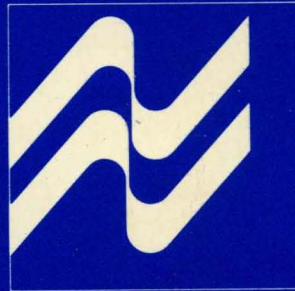


**INTERFACE
BIPOLAR LSI
BIPOLAR MEMORY
PROGRAMMABLE LOGIC
DATABOOK**

**NATIONAL
SEMICONDUCTOR
CORPORATION**



**INTERFACE
BIPOLAR LSI
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PROGRAMMABLE LOGIC**

DATABOOK

National Semiconductor

1983

**INTERFACE
BIPOLAR LSI
BIPOLAR MEMORY
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DATABOOK**

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All physical dimensions appear at the end of the databook.



Introduction

The 1983 edition of the National Semiconductor Interface / Bipolar LSI / Bipolar Memory / Programmable Logic Databook is the most comprehensive available. It contains complete specifications on these high technology products, as well as applications information, product selection and cross reference guides.

Quality and Reliability

As electronic systems become more and more complex, the need for consistently high quality integrated circuits becomes increasingly important. Having recognized this need as far back as the 1970s, National Semiconductor initiated a unique, company-wide Quality Improvement Program. The results have been dramatic and, we believe, unmatched in this industry. Over the years, National has regularly been named by many major customers as "Quality Manufacturer of the Year." We are proud of our success, which sets a standard for others to achieve. And yet our quest for perfection is ongoing, so that customers can continue to rely on National Semiconductor integrated circuits and products in their system designs.



Einführung

Die 1983er Ausgabe des National Semiconductor Interface/Bipolar LSI/Bipolar Memory/Programmable Logic Datenbuches ist die umfassendste Ausgabe die jemals zur Verfügung stand. Sie beinhaltet komplette Spezifikationen dieser hochtechnologischen Produkte so wie Angaben über Anwendungsmöglichkeiten, Produktselektion und Referenzlisten.

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Introduction

L'édition 1983 du catalogue National Semiconductor Interface/Bipolar LSI/Bipolar Memory/Programmable Logic est le plus accessible des catalogues disponibles. Le contenu de cette édition spécifie complètement ces produits à technologie de pointe et décrit des exemples d'application, plus une sélection de produits avec une liste de correspondance.

Qualité et Fiabilité

La complexité croissante des systèmes électroniques demande des circuits intégrés de plus en plus haute qualité. Conscient de ce besoin dès les années '70 National Semiconductor fut à l'origine d'un programme unique accentuant la qualité de tous ses produits. Les résultats furent spectaculaires et inégalés. Depuis National Semiconductor a reçu la distinction pour la qualité de ses produits de la part de ses clients. Nous sommes fiers de ce succès qui force les autres à suivre nos standards. Notre recherche de la perfection se poursuit apportant la confiance pour nos clients en nos produits et leur utilisation pour leurs systèmes.

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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Section 1 Transmission Line Drivers/Receivers

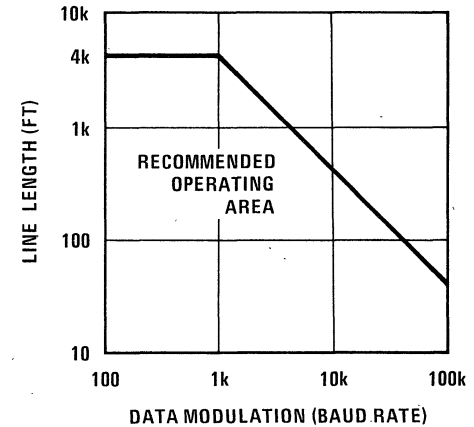


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-55°C to +125°C	0°C to +70°C		
—	DS1488	Quad Line Driver	1-7
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*DS1692	DS3692	TRI-STATE Differential Line Driver	1-42
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—	DS3696	Differential TRI-STATE Bus/Line Transceiver	1-47
—	DS3697	Differential TRI-STATE Bus/Line Transceiver/ Repeater	1-47
—	DS3698	Differential TRI-STATE Bus/Line Transceiver/ Repeater	1-47
*DS55107	DS75107	Dual Line Receiver	1-25
—	DS75207	Dual Line Receiver	1-25
*DS55108	DS75108	Dual Line Receiver	1-25
—	DS75208	Dual Line Receiver	1-25
*DS55113	DS75113	Dual TRI-STATE Differential Line Driver	1-52
*DS55114	DS75114	Dual Differential Line Driver	1-57
*DS55115	DS75115	Dual Differential Line Receiver	1-61
DS55121	DS75121	Dual Line Driver	1-66
*DS55122	DS75122	Triple Line Receiver	1-68
—	DS75123	Dual Line Driver	1-71
—	DS75124	Triple Line Receiver	1-73
—	DS75125	Seven-Channel Line Receiver	1-76
—	DS75127	Seven-Channel Line Receiver	1-76
—	DS75128	Eight-Channel Line Receiver	1-80
—	DS75129	Eight-Channel Line Receiver	1-80
—	DS75150	Dual Line Driver	1-84
—	DS75154	Dual Line Receiver	1-87
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*DS7820A	DS8820A	Dual Line Receiver	1-94
*DS78C20	DS88C20	Dual CMOS Compatible Differential Line Receiver	1-98
*DS7830	DS8830	Dual Differential Line Driver	1-101
*DS7831	DS8831	Dual TRI-STATE Line Driver	1-104
*DS7832	DS8832	Dual TRI-STATE Line Driver	1-104
*DS78C120	DS88C120	Dual CMOS Compatible Line Receiver	1-109
*DS78LS120	DS88LS120	Dual Differential Line Receiver	1-116
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MM78C30	MM88C30	Dual Differential Line Driver	CMOS
—	AN-22	Integrated Circuits for Digital Data Transmission	1-123
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—	AN-214	Transmission Line Drivers and Receivers for EIA Standards RS-422 and RS-423	1-145
—	AN-216	Summary of Electrical Characteristics of Some Well Known Digital Interface Standards	1-155

UNBALANCED (COMMON-MODE) TRANSMISSION DRIVERS AND RECEIVERS

Unbalanced data transmission isn't recommended for long lines or fast data rates. Unbalanced line receivers are sensitive to common-mode noise, such as ground IR noise and induced reactive noise. Unbalanced line drivers should employ slew rate control to prevent near end crosstalk to other wires in the cable. Receivers should employ response control and hysteresis. Unbalanced data transmission was preferred because the cabling requires only one wire/signal plus ground and the circuits were lower cost. New lower cost circuits available today negate the last argument. Many old interfaces such as RS-232 will continue to exist for many years, and so will the application for unbalanced circuits.

Line length is a function of data rate (baud) and slew rate. The recommended safe operating area (line length vs baud rate is shown below for 24 AWG wire. It assumes that a differential line receiver is used which is referenced at the driver ground. Also, it assumes that the driver slew rate is between 0.1 to 0.3 times the reciprocal of the baud rate (minimum unit interval). Otherwise, line lengths greater than 50 feet are not recommended. The exception to line length is the 360 I/O coaxial interface. The coaxial provides improved grounding and eliminates crosstalk.



UNBALANCED DRIVERS

Propagation Delay (ns)	Output Voltage (V)	Output Current (mA)	Slew Rate Control	Party-Line Application	Open-Collector or Open Emitter	Power Supplies (V)	Standard	Circuits/Package	Device Number		Comment	Page No.
									Commercial 0°C to +70°C	Military -55°C to +125°C		
200	±6 or ±9	±6	I _{OS} /C			±9 or ±15	RS-232	4	DS1488			1-7
60	±5	±10	I _{OS} /C			±12	RS-232	2	DS75150			1-84
200	±2	±20	CEXT	Yes	TRI-STATE®	5 or ±5	RS-423	4	DS3691	DS1691A		1-37
200	±2	±20	CEXT	Yes	TRI-STATE	5 or ±5	MIL 188-114	4	DS3692	DS1692	±10V common-mode range	1-42
10	2.4	-100		Yes	Emitter	5	360 I/O	2	DS75121	DS55121	50Ω coax. driver	1-66
10	2.4	-100		Yes	Emitter	5	360 I/O	2	DS75123		50Ω coax. driver (IBM)	1-71
20	0.7	300		Yes	Emitter and Collector	5		2	DS75450			3-51
18	0.7	300		Yes	Collector	5		2	DS75451	DS55451		3-51
26	0.7	300		Yes	Collector	5		2	DS75452	DS55452		3-51
18	0.7	300		Yes	Collector	5		2	DS75453	DS55453		3-51
27	0.7	300		Yes	Collector	5		2	DS75454	DS55454		3-51

UNBALANCED RECEIVERS

Propagation Delay (ns)	Threshold Sensitivity (V)	Input Range (V)	Hysteresis (mV)	Response Control	Strobed or TRI-STATE®	Power Supplies (V)	Standard	Circuits/Package	Device Number		Comments	Page No.
									Commercial 0°C to +70°C	Military -55°C to +125°C		
30	3	±25	250	CEXT		5	RS-232	4	DS1489			1-10
30	3	±25	1150	CEXT		5	RS-232	4	DS1489A		Preferential in applications to DS1489	1-10
22	3	±25	800	CEXT		5 or 15	RS-232	4	DS75154			1-87
50	±0.2	±25	50	CEXT	Strobed	5	RS-423	2	DS88LS120	DS78LS120	Fail-safe	1-116
50	±0.2	±25	50	CEXT	Strobed	5 to 15	RS-423	2	DS88C120	DS78C120	Fail-safe	1-109
17	±0.2	±7	100		TRI-STATE	5	RS-423	4	DS26LS32C	DS26LS32M		1-15
23	±0.2	±7	100		TRI-STATE	5	RS-423	4	DS26LS32AC		Fail-safe	1-15
17	±0.5	±15	200		TRI-STATE	5	RS-423	4	DS26LS33C	DS26LS33M		1-15
23	±0.5	±15	200		TRI-STATE	5	RS-423	4	DS26LS33AC		Fail-safe	1-15
25	±0.1	±15	100		TRI-STATE	5	RS-423	4	DS3486			1-18
20	0.8 to 2	7	600		Strobed	5	360 I/O	3	DS75122	DS55122	50Ω coax. receiver	1-68
20	0.8 to 2	7	400		Strobed	5	360 I/O	3	DS75124	DS55124	50Ω coax. receiver (IBM)	1-73
16	0.7 to 1.7	-2/7				5	360 I/O	7	DS75125		IBM coax. receiver	1-76
16	0.7 to 1.7	-2/7				5	360 I/O	7	DS75127		IBM coax. receiver	1-76
16	0.7 to 1.7	-2/7				5	360 I/O	8	DS75128		IBM coax. receiver	1-80
16	0.7 to 1.7	-2/7				5	360 I/O	8	DS75129		IBM coax. receiver	1-80

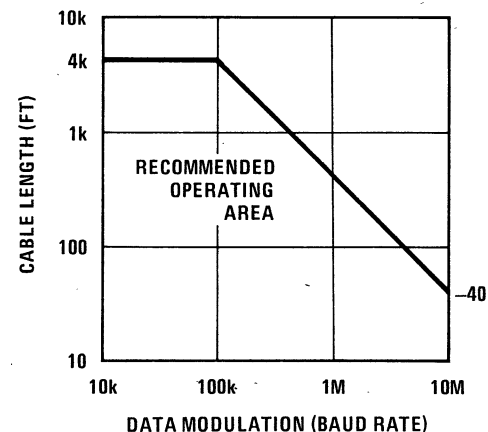
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BALANCED (DIFFERENTIAL) TRANSMISSION LINE DRIVERS AND RECEIVERS

Balanced data transmission is applicable for long lines in the presence of high common-mode noise. Balanced circuits don't generate much noise and are also not susceptible to common-mode noise, and therefore work well in long lines when cabled with other signals.

Line length is a function of data rate (baud) and the combination of IR drop and skin effect. Refer to AN-108 and AN-22. The recommended safe operating area (line length vs baud rate) is shown for 24 AWG wire.



BALANCED DRIVERS

Propagation Delay (ns)	VOL (V)/ IOL (mA)	VOH (V)/ IOH (mA)	Party Line Application	TRI-STATE®	Open-Collector	Power Supplies (V)	Standard	Circuits/ Package	Device Number		Comments	Page No.
									Commercial 0°C to +70°C	Military -55°C to +125°C		
10	0.5/40	1.8/-40				5		2	DS8830	DS7830		1-101
100	0.4/11	2.9/-57				5 or 15		2	MM88C30	MM78C30	CMOS comparator	CMOS
100	0.4/11	2.9/-57				5 or 15		2	MM88C29	MM78C29	Non-inverting MM88C30	CMOS
10	0.5/40	1.8/-40	Yes	TRI-STATE		5		2	DS8831	DS7831		1-104
10	0.5/40	1.8/-40	Yes	TRI-STATE		5		2	DS8832	DS7832	DS8831 without V _{CC} clamp diode	1-104
13	0.4/40	2/-40	Yes	TRI-STATE	Optional	5		2	DS75113	DS55113		1-52
15	0.4/40	2/-40			Optional	5		2	DS75114	DS55114		1-57
200	-2/20	2/-20	Yes	TRI-STATE		5 or ±5	RS-422	2	DS3691	DS1691A		1-37
200	-2/20	2/-20	Yes	TRI-STATE		5 or ±5		2	DS3692	DS1692	±10V TRI-STATE common-mode range	1-42
15			Yes	TRI-STATE		5	RS-485	1	DS3695		RS-485 Transceiver	1-47
15			Yes	TRI-STATE		5	RS-485	1	DS3696		RS-485 Transceiver	1-47
15			Yes	TRI-STATE		5	RS-485	1	DS3697		RS-485 Transceiver	1-47
15			Yes	TRI-STATE		5	RS-485	1	DS3698		RS-485 Transceiver	1-47
12	0.5/40	2.5/-20	Yes	TRI-STATE		5	RS-422	4	DS26LS31C	DS26LS31M		1-12
15	0.5/48	2/-50	Yes	TRI-STATE		5	RS-422	4	DS3487	DS3587		1-22

BALANCED RECEIVERS

Propagation Delay (ns)	Threshold Sensitivity (mV)	Common-Mode Range (V)	Hysteresis (mV)	Response Control	Strobed or TRI-STATE®	Power Supplies (V)	Standard	Circuits/Package	Device Number		Comments	Page No.
									Commercial	Military		
									0°C to +70°C	-55°C to +125°C		
40	±1000	±15		Yes	Strobed	5		2	DS8820	DS7820		1-91
30	±1000	±15		Yes	Strobed	5		2	DS8820A	DS7820A		1-94
60	±200	±10	50	Yes	Strobed	5 to 15	RS-422	2	DS88C20	DS78C20	CMOS compatible	1-98
60	±200	±10	50	Yes	Strobed	5 to 15	RS-422	2	DS88C120	DS78C120	Fail-safe, CMOS compatible	1-109
50	±200	±10	50	Yes	Strobed	5	RS-422	2	DS88LS120	DS78LS120	Fail-safe	1-116
20	±500	±15		Yes	Strobed	5		2	DS75115	DS55115		1-61
17	±200	±7	100		TRI-STATE	5	RS-422	4	DS26LS32C	DS26LS32M		1-15
17	±200	±7	100		TRI-STATE	5	RS-422	4	DS26LS32AC		Fail-Safe	1-15
17	±500	±15	200		TRI-STATE	5	RS-422	4	DS26LS33C	DS26LS33M		1-15
17	±500	±15	200		TRI-STATE	5	RS-422	4	DS26LS33AC		Fail-Safe	1-15
25	±200	±10	80		TRI-STATE	5	RS-422	4	DS3486			1-18
10	±25	±3			TRI-STATE	±5		4	DS3650	DS1650		1-31
10	±25	±3			Strobed	±5		4	DS3652	DS1652		1-31
22	±200	+12, -7	70		TRI-STATE	5	RS-485	1	DS3695		RS-485 Transceiver	1-47
22	±200	+12, -7	70		TRI-STATE	5	RS-485	1	DS3696		RS-485 Transceiver	1-47
22	±200	+12, -7	70		TRI-STATE	5	RS-485	1	DS3697		RS-485 Transceiver	1-47
22	±200	+12, -7	70		TRI-STATE	5	RS-485	1	DS3698		RS-485 Transceiver	1-47
17	±25	±3			Strobed	±5		2	DS75107	DS55107		1-25
17	±10	±3			Strobed	±5		2	DS75207			1-25
17	±25	±3			Strobed	±5		2	DS75108	DS55108		1-25
17	±10	±3			Strobed	±5		2	DS75208			1-25
17	±25	±3			TRI-STATE	±5		2	DS3603	DS1603		1-25

Note. Voltage comparators (such as the LM710) have good threshold sensitivity and good common-mode range and, in turn, also make good line receivers. These comparators generally use 2 power supplies (±15V), which may not be available in some digital systems.

DS1488 Quad Line Driver

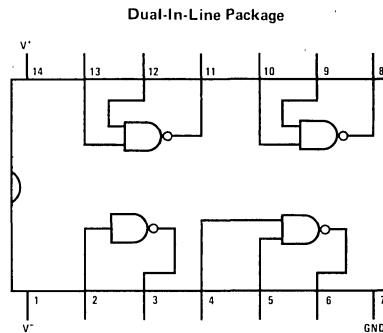
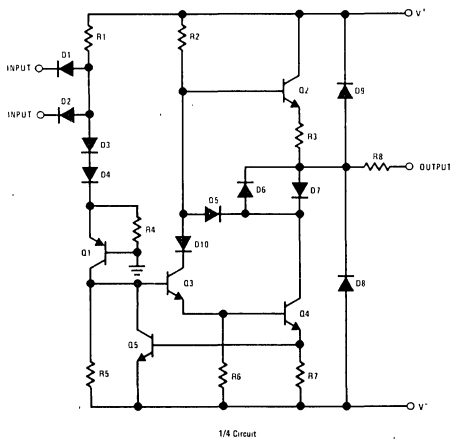
General Description

The DS1488 is a quad line driver which converts standard TTL input levels through one stage of inversion to output levels which meet EIA Standard No. RS-232C and CCITT Recommendation V. 24.

Features

- Current limited output ±10 mA typ
- Power-off source impedance 300Ω min
- Simple slew rate control with external capacitor
- Flexible operating supply range
- Inputs are TTL/LS compatible

Schematic and Connection Diagrams

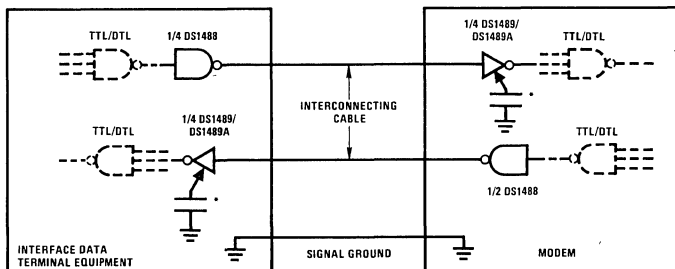


TOP VIEW

Order Number DS1488J or DS1488N
See NS Package J14A or N14A

Typical Applications

RS232C Data Transmission



*Optional for noise filtering

Absolute Maximum Ratings (Note 1)

Supply Voltage	
V^+	+15V
V^-	-15V
Input Voltage (V_{IN})	$-15V \leq V_{IN} \leq 7.0V$
Output Voltage	$\pm 15V$
Operating Temperature Range	$0^\circ C$ to $+75^\circ C$
Storage Temperature Range	$-65^\circ C$ to $+150^\circ C$
Maximum Power Dissipation* at $25^\circ C$	
Cavity Package	1364 mW
Molded Package	1280 mW
Lead Temperature (Soldering, 10 sec)	$300^\circ C$

*Derate cavity package 9.1 mW/ $^\circ C$ above $25^\circ C$; derate molded package 10.2 mW/ $^\circ C$ above $25^\circ C$.

Electrical Characteristics (Notes 2 and 3) $V_{CC+} = 9V$, $V_{CC-} = -9V$ unless otherwise specified

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
I_{IL}	Logical "0" Input Current	$V_{IN} = 0V$			-1.0	-1.3	mA
I_{IH}	Logical "1" Input Current	$V_{IN} = +5.0V$			0.005	10.0	μA
V_{OH}	High Level Output Voltage	$R_L = 3.0 k\Omega$, $V_{IN} = 0.8V$	$V^+ = 9.0V, V^- = -9.0V$	6.0	7.0		V
			$V^+ = 13.2V, V^- = -13.2V$	9.0	10.5		V
V_{OL}	Low Level Output Voltage	$R_L = 3.0 k\Omega$, $V_{IN} = 1.9V$	$V^+ = 9.0V, V^- = -9.0V$		-6.8	-6.0	V
			$V^+ = 13.2V, V^- = -13.2V$		-10.5	-9.0	V
I_{OS}^+	High Level Output Short-Circuit Current	$V_{OUT} = 0V, V_{IN} = 0.8V$		-6.0	-10.0	-12.0	mA
I_{OS}^-	Low Level Output Short-Circuit Current	$V_{OUT} = 0V, V_{IN} = 1.9V$		6.0	10.0	12.0	mA
R_{OUT}	Output Resistance	$V^+ = V^- = 0V, V_{OUT} = \pm 2V$		300			Ω
I_{CC}^+	Positive Supply Current (Output Open)	$V_{IN} = 1.9V$	$V^+ = 9.0V, V^- = -9.0V$		15.0	20.0	mA
			$V^+ = 12V, V^- = -12V$		19.0	25.0	mA
			$V^+ = 15V, V^- = -15V$		25.0	34.0	mA
		$V_{IN} = 0.8V$	$V^+ = 9.0V, V^- = -9.0V$		4.5	6.0	mA
			$V^+ = 12V, V^- = -12V$		5.5	7.0	mA
			$V^+ = 15V, V^- = -15V$		8.0	12.0	mA
I_{CC}^-	Negative Supply Current (Output Open)	$V_{IN} = 1.9V$	$V^+ = 9.0V, V^- = -9.0V$		-13.0	-17.0	mA
			$V^+ = 12V, V^- = -12V$		-18.0	-23.0	mA
			$V^+ = 15V, V^- = -15V$		-25.0	-34.0	mA
		$V_{IN} = 0.8V$	$V^+ = 9.0V, V^- = -9.0V$		-0.001	-0.015	mA
			$V^+ = 12V, V^- = -12V$		-0.001	-0.015	mA
			$V^+ = 15V, V^- = -15V$		-0.01	-2.5	mA
P_d	Power Dissipation	$V^+ = 9.0V, V^- = -9.0V$			252	333	mW
		$V^+ = 12V, V^- = -12V$			444	576	mW

Switching Characteristics ($V_{CC} = 9V$, $V_{EE} = -9V$, $T_A = 25^\circ C$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{pd1}	Propagation Delay to a Logical "1"	$R_L = 3.0 k\Omega, C_L = 15 pF, T_A = 25^\circ C$		230	350	ns
t_{pd0}	Propagation Delay to a Logical "0"	$R_L = 3.0 k\Omega, C_L = 15 pF, T_A = 25^\circ C$		70	175	ns
t_r	Rise Time	$R_L = 3.0 k\Omega, C_L = 15 pF, T_A = 25^\circ C$		75	100	ns
t_f	Fall Time	$R_L = 3.0 k\Omega, C_L = 15 pF, T_A = 25^\circ C$		40	75	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the $0^\circ C$ to $+75^\circ C$ temperature range for the DS1488.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Applications

By connecting a capacitor to each driver output the slew rate can be controlled utilizing the output current limiting characteristics of the DS1488. For a set slew rate the appropriate capacitor value may be calculated using the following relationship

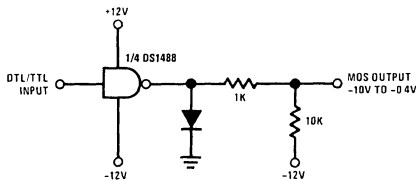
$$C = I_{SC} (\Delta T / \Delta V)$$

where C is the required capacitor, I_{SC} is the short circuit current value, and $\Delta V / \Delta T$ is the slew rate.

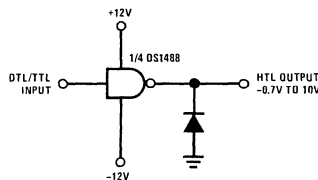
RS232C specifies that the output slew rate must not exceed 30V per microsecond. Using the worst case output short circuit current of 12 mA in the above equation, calculations result in a required capacitor of 400 pF connected to each output.

Typical Applications (Continued)

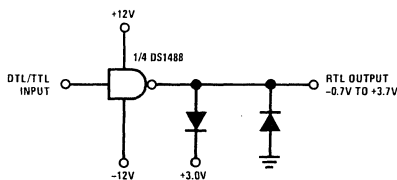
DTL/TTL-to-MOS Translator



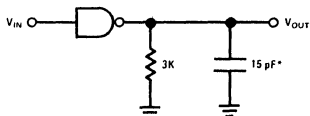
DTL/TTL-to-HTL Translator



DTL/TTL-to-RTL Translator

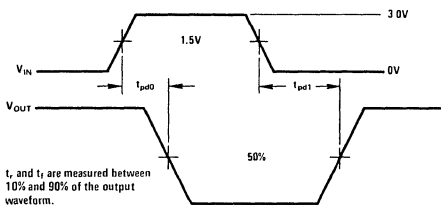


AC Load Circuit



* C_L includes probe and jig capacitance.

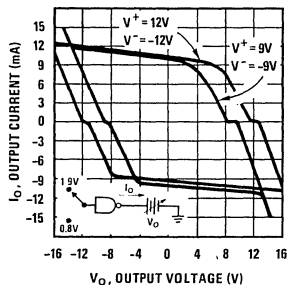
Switching Time Waveforms



t_r and t_f are measured between 10% and 90% of the output waveform.

Typical Performance Characteristics

Output Voltage and Current-Limiting Characteristics



DS1489/DS1489A Quad Line Receiver

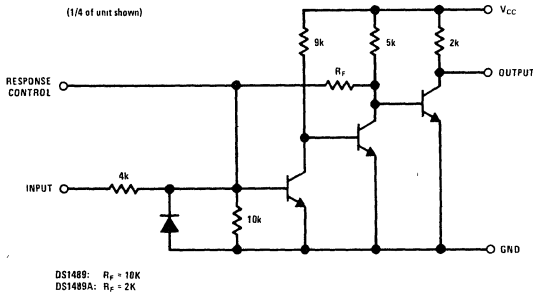
General Description

The DS1489/DS1489A are quad line receivers designed to interface data terminal equipment with data communications equipment. They are constructed on a single monolithic silicon chip. These devices satisfy the specifications of EIA standard No. RS232C. The DS1489/DS1489A meet and exceed the specifications of MC1489/MC1489A and are pin-for-pin replacements.

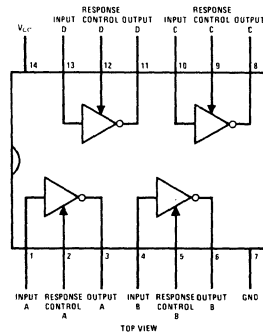
Features

- Four totally separate receivers per package
- Programmable threshold
- Built-in input threshold hysteresis
- "Fail safe" operating mode
- Inputs withstand $\pm 30V$

Schematic and Connection Diagrams

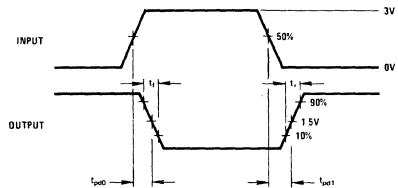
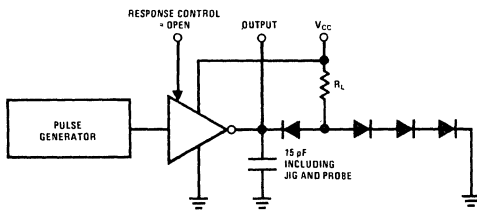


Dual-In-Line Package

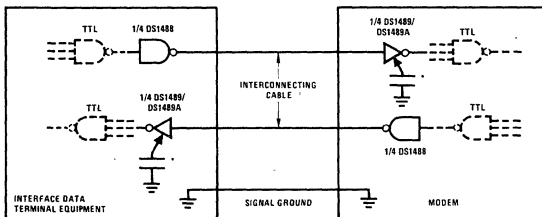


Order Number DS1489J, DS1489AJ,
 DS1489N or DS1489AN
 See NS Package J14A or N14A

AC Test Circuit and Voltage Waveforms

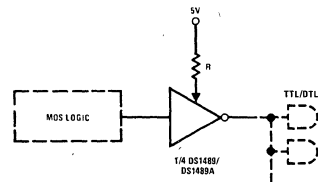


Typical Applications



*Optional for noise filtering.

RS232C Data Transmission



MOS to TTL/LS Translator

Absolute Maximum Ratings (Note 1)

The following apply for $T_A = 25^\circ\text{C}$ unless otherwise specified.

Power Supply Voltage	10V
Input Voltage Range	$\pm 30\text{V}$
Output Load Current	20 mA
Power Dissipation (Note 2)	1W
Operating Temperature Range	0°C to $+75^\circ\text{C}$
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW

*Derate cavity package 8.7 mW/ $^\circ\text{C}$ above 25°C ; derate molded package 9.7 mW/ $^\circ\text{C}$ above 25°C .

Electrical Characteristics (Notes 2, 3 and 4)

DS1489/DS1489A: The following apply for $V_{CC} = 5.0\text{V} \pm 1\%$, $0^\circ\text{C} \leq T_A \leq +75^\circ\text{C}$ unless otherwise specified.

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS	
V_{TH}	Input High Threshold Voltage	$V_{OUT} \leq 0.45\text{V}$, $I_{OUT} = 10\text{ mA}$	DS1489	$T_A = 25^\circ\text{C}$	1.0	1.25	1.5	V
					0.9		1.6	V
		DS1489A	$T_A = 25^\circ\text{C}$	1.75	2.00	2.25	V	
				1.55		2.40	V	
V_{TL}	Input Low Threshold Voltage	$V_{OUT} \geq 2.5\text{V}$, $I_{OUT} = -0.5\text{ mA}$	$T_A = 25^\circ\text{C}$	0.75	1.00	1.25	V	
				0.65		1.35	V	
I_{IN}	Input Current	$V_{IN} = +25\text{V}$		+3.6	+5.6	+8.3	mA	
		$V_{IN} = -25\text{V}$		-3.6	-5.6	-8.3	mA	
		$V_{IN} = +3\text{V}$		+0.43	+0.53		mA	
		$V_{IN} = -3\text{V}$		-0.43	-0.53		mA	
V_{OH}	Output High Voltage	$I_{OUT} = -0.5\text{ mA}$	$V_{IN} = 0.75\text{V}$	2.6	3.8	5.0	V	
			Input = Open	2.6	3.8	5.0	V	
V_{OL}	Output Low Voltage	$V_{IN} = 3.0\text{V}$, $I_{OUT} = 10\text{ mA}$			0.33	0.45	V	
I_{SC}	Output Short Circuit Current	$V_{IN} = 0.75\text{V}$			3.0		mA	
I_{CC}	Supply Current	$V_{IN} = 5.0\text{V}$			14	26	mA	
P_d	Power Dissipation	$V_{IN} = 5.0\text{V}$			70	130	mW	

Switching Characteristics ($V_{CC} = 5\text{V}$, $T_A = 25^\circ\text{C}$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{pd1}	Input to Output "High" Propagation Delay	$R_L = 3.9\text{k}$, (Figure 1) (ac Test Circuit)		28	85	ns
t_{pd0}	Input to Output "Low" Propagation Delay	$R_L = 390\Omega$, (Figure 1) (ac Test Circuit)		20	50	ns
t_r	Output Rise Time	$R_L = 3.9\text{k}$, (Figure 1) (ac Test Circuit)		110	175	ns
t_f	Output Fall Time	$R_L = 390\Omega$, (Figure 1) (ac Test Circuit)		9	20	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to $+75^\circ\text{C}$ temperature range for the DS1489 and DS1489A.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: These specifications apply for response control pin = open.



**National
Semiconductor**

**Transmission Line
Drivers/Receivers**

**DS26LS31C/DS26LS31M Quad High Speed
Differential Line Driver**

General Description

The DS26LS31 is a quad differential line driver designed for digital data transmission over balanced lines. The DS26LS31 meets all the requirements of EIA Standard RS-422 and Federal Standard 1020. It is designed to provide unipolar differential drive to twisted-pair or parallel-wire transmission lines.

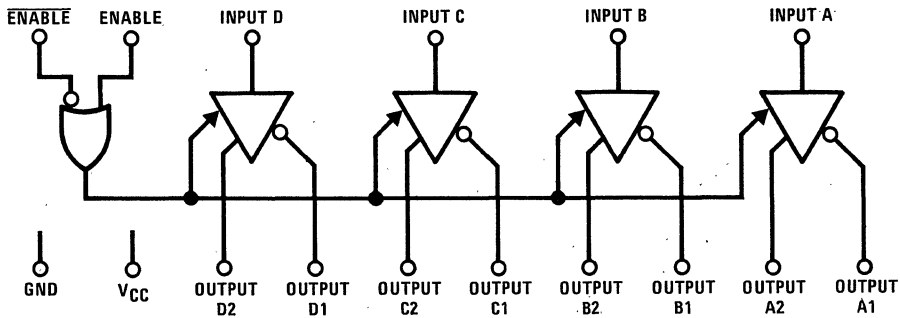
The circuit provides an enable and disable function common to all four drivers. The DS26LS31 features TRI-STATE® outputs and logically ANDed complementary outputs. The inputs are all LS compatible and are all one unit load.

The DS26LS31 features a power up/down protection circuit which TRI-STATes the outputs during power up or down preventing erroneous glitches on the transmission lines.

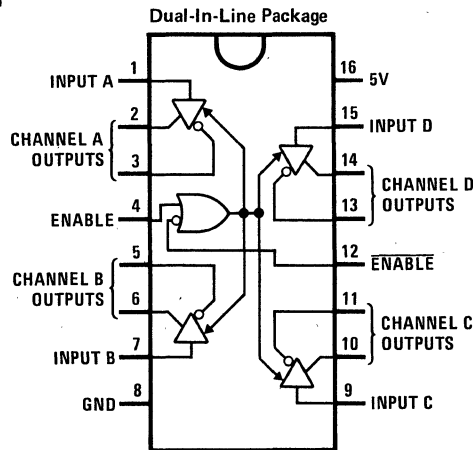
Features

- Output skew — 2.0 ns typical
- Input to output delay — 10 ns
- Operation from single 5V supply
- 16-pin hermetic and molded DIP package
- Outputs won't load line when $V_{CC} = 0$
- Four line drivers in one package for maximum package density
- Output short-circuit protection
- Complementary outputs
- Meets the requirements of EIA Standard RS-422
- Pin compatible with AM26LS31
- Available in military and commercial temperature range
- Glitch free power up/down

Logic Diagram



Connection Diagram



TOP VIEW

Order Number DS26LS31CJ, DS26LS31CN or
DS26LS31MJ

See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	7V
Output Voltage	5V
Output Voltage (Power OFF)	-0.25V to 6V
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}			
DS26LS31M	4.5	5.5	V
DS26LS31	4.75	5.25	V
Temperature, T_A			
DS26LS31M	-55	+125	°C
DS26LS31	0	+70	°C

Electrical Characteristics (Notes 2, 3 and 4)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{OH} Output High Voltage	$I_{OH} = -20$ mA	2.5			V
V_{OL} Output Low Voltage	$I_{OL} = 20$ mA			0.5	V
V_{IH} Input High Voltage		2.0			V
V_{IL} Input Low Voltage				0.8	V
I_{IL} Input Low Current	$V_{IN} = 0.4$ V		-40	-200	μ A
I_{IH} Input High Current	$V_{IN} = 2.7$ V			20	μ A
I_I Input Reverse Current	$V_{IN} = 7$ V			0.1	mA
I_O TRI-STATE Output Current	$V_O = 2.5$ V			20	μ A
	$V_O = 0.5$ V			-20	μ A
V_{CL} Input Clamp Voltage	$I_{IN} = -18$ mA			-1.5	V
I_{SC} Output Short-Circuit Current		-30		-150	mA
I_{CC} Power Supply Current	All Outputs Disabled or Active		35	60	mA

Switching Characteristics $V_{CC} = 5$ V, $T_A = 25^\circ$ C

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{PLH} Input to Output	$C_L = 30$ pF		10	15	ns
t_{PHL} Input to Output	$C_L = 30$ pF		10	15	ns
Skew Output to Output	$C_L = 30$ pF		2.0	6.0	ns
t_{LZ} Enable to Output	$C_L = 10$ pF, S2 Open		15	35	ns
t_{HZ} Enable to Output	$C_L = 10$ pF, S1 Open		15	25	ns
t_{ZL} Enable to Output	$C_L = 30$ pF, S2 Open		20	30	ns
t_{ZH} Enable to Output	$C_L = 30$ pF, S1 Open		20	30	ns

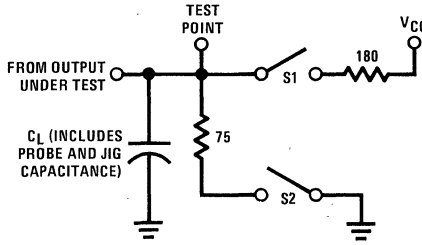
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the -55° C to $+125^\circ$ C temperature range for the DS26LS31M and across the 0° C to $+70^\circ$ C range for the DS26LS31. All typicals are given for $V_{CC} = 5$ V and $T_A = 25^\circ$ C.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

AC Test Circuit and Switching Time Waveforms



Note. S1 and S2 of load circuit are closed except where shown.

FIGURE 1. AC Test Circuit

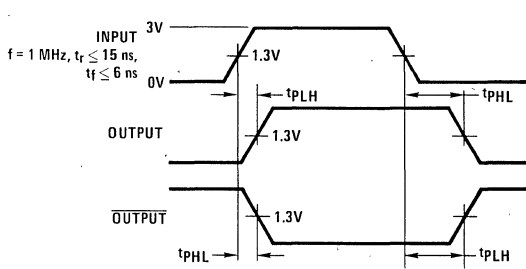


FIGURE 2. Propagation Delays

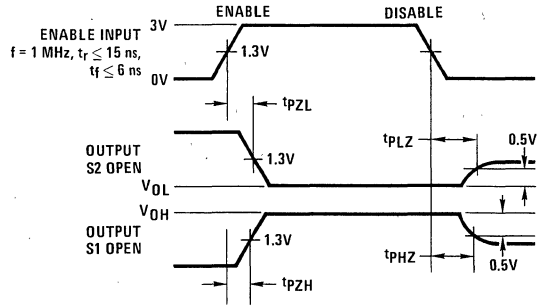
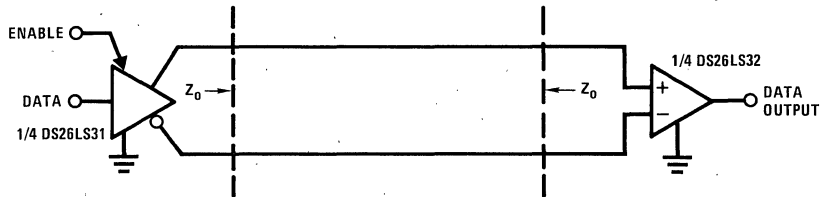


FIGURE 3. Enable and Disable Times

Typical Applications

Two-Wire Balanced System, RS-422





DS26LS32C/DS26LS32M, DS26LS32AC, DS26LS33C/DS26LS33M, DS26LS33AC Quad Differential Line Receivers

General Description

The DS26LS32 and DS26LS32A are quad differential line receivers designed to meet the RS-422, RS-423 and Federal Standards 1020 and 1030 for balanced and unbalanced digital data transmission.

The DS26LS32 and DS26LS32A have an input sensitivity of 200 mV over the input voltage range of $\pm 7V$ and the DS26LS33 and DS26LS33A have an input sensitivity of 500 mV over the input voltage range of $\pm 15V$.

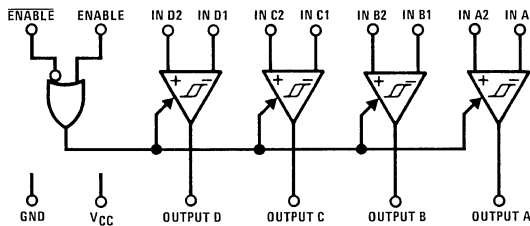
Both the DS26LS32A and DS26LS33A differ in function from the popular DS26LS32 and DS26LS33 in that input fail-safe circuitry is provided for each receiver, which causes the outputs to go to a logic "1" state when the inputs are open.

Each version provides an enable and disable function common to all four receivers and features TRI-STATE® outputs with 8 mA sink capability. Constructed using low power Schottky processing, these devices are available over the full military and commercial operating temperature ranges.

Features

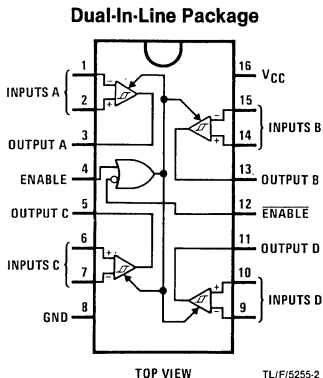
- High differential or common-mode input voltage ranges of $\pm 7V$ on the DS26LS32 and DS26LS32A and $\pm 15V$ on the DS26LS33 and DS26LS33A
- $\pm 0.2V$ sensitivity over the input voltage range on the DS26LS32 and DS26LS32A, $\pm 0.5V$ sensitivity on the DS26LS33 and DS26LS33A
- Input fail-safe circuitry on the DS26LS32A and DS26LS33A
- DS26LS32 and DS26LS32A meet all requirements of RS-422 and RS-423
- 6k minimum input impedance
- 100 mV input hysteresis on the DS26LS32 and DS26LS32A, 200 mV on the DS26LS33 and DS26LS33A
- Operation from a single 5V supply
- TRI-STATE drive, with choice of complementary output enables for receiving directly onto a data bus
- Pin replacement for Advanced Micro Devices AM26LS32

Logic Diagram



TLI/F5255-1

Connection Diagram



Truth Table

ENABLE	ENABLE	Input	Output
0	1	X	Hi-Z
See Note Below		$V_{ID} \geq V_{TH}$ (Max)	1
		$V_{ID} \leq V_{TH}$ (Min)	0
		Open	1*

Hi-Z = TRI-STATE

*DS26LS32A and DS26LS33A only

Note: Input conditions may be any combination not defined for ENABLE and ENABLE.

**Order Number DS26LS32MJ, DS26LS32CJ,
DS26LS32CN, DS26LS32ACJ, DS26LS32ACN,
DS26LS33MJ, DS26LS33CJ, DS26LS33CN,
DS26LS33ACJ or DS26LS33ACN
See NS Package J16A or N16A**

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Common-Mode Range	± 25V
Differential Input Voltage	± 25V
Enable Voltage	7V
Output Sink Current	50 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Storage Temperature Range	- 65°C to + 165°C
Lead Temperature (Soldering, 10 seconds)	300°C

* Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})			
DS26LS32M, DS26LS33M (MIL)	4.5	5.5	V
DS26LS32C, DS26LS33C (MIL)	4.75	5.25	V
DS26LS32AC, DS26LS33AC (COML)			
Temperature (T_A)			
DS26LS32M, DS26LS33M (MIL)	- 55	+ 125	°C
DS26LS32C, DS26LS33C (MIL)	0	+ 70	°C
DS26LS32AC, DS26LS33AC (COML)			

Electrical Characteristics over the operating temperature range unless otherwise specified (Notes 2, 3 and 4)

Parameter	Conditions	Min	Typ	Max	Units	
V_{TH} Differential Input Voltage	$V_{OUT} = V_{OH}$ or V_{OL} DS26LS32, DS26LS32A, - 7V ≤ V_{CM} ≤ + 7V	- 0.2	± 0.07	0.2	V	
	DS26LS33, DS26LS33A, - 15V ≤ V_{CM} ≤ + 15V	- 0.5	± 0.14	0.5	V	
R_{IN} Input Resistance	- 15V ≤ V_{CM} ≤ + 15V (One Input AC GND)	6.0	8.5		kΩ	
I_{IN} Input Current (Under Test)	$V_{IN} = 15V$, Other Input - 15V ≤ V_{IN} ≤ + 15V			2.3	mA	
	$V_{IN} = - 15V$, Other Input - 15V ≤ V_{IN} ≤ + 15V			- 2.8	mA	
V_{OH} Output High Voltage	$V_{CC} = \text{Min}$, $\Delta V_{IN} = 1V$, $V_{ENABLE} = 0.8V$, $I_{OH} = - 440 \mu A$	2.7	4.2		V	
	Commercial	2.5	4.2		V	
V_{OL} Output Low Voltage	$V_{CC} = \text{Min}$, $\Delta V_{IN} = - 1V$, $V_{ENABLE} = 0.8V$			0.4	V	
	$I_{OL} = 4 \text{ mA}$			0.45	V	
V_{IL} Enable Low Voltage				0.8	V	
V_{IH} Enable High Voltage		2.0			V	
V_I Enable Clamp Voltage	$V_{CC} = \text{Min}$, $I_{IN} = - 18 \text{ mA}$			- 1.5	V	
I_O OFF-State (High Impedance) Output Current	$V_{CC} = \text{Max}$			20	μA	
	$V_O = 2.4V$ $V_O = 0.4V$			- 20	μA	
I_{IL} Enable Low Current	$V_{IN} = 0.4V$			- 0.36	mA	
I_{IH} Enable High Current	$V_{IN} = 2.7V$			20	μA	
I_{SC} Output Short-Circuit Current	$V_O = 0V$, $V_{CC} = \text{Max}$, $\Delta V_{IN} = 1V$	- 15		- 85	mA	
I_{CC} Power Supply Current	$V_{CC} = \text{Max}$, All $V_{IN} = \text{GND}$, Outputs Disabled			52	70	mA
	DS26LS32, DS26LS32A DS26LS33, DS26LS33A			57	80	mA
I_I Input High Current	$V_{IN} = 5.5V$			100	μA	
V_{HYST} Input Hysteresis	$T_A = 25^\circ C$, $V_{CC} = 5V$, $V_{CM} = 0V$			100	mV	
	DS26LS32, DS26LS32A DS26LS33, DS26LS33A			200	mV	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max or min are so classified on absolute value basis.

Note 3: All typical values are $V_{CC} = 5V$, $T_A = 25^\circ C$.

Note 4: Only one output at a time should be shorted.

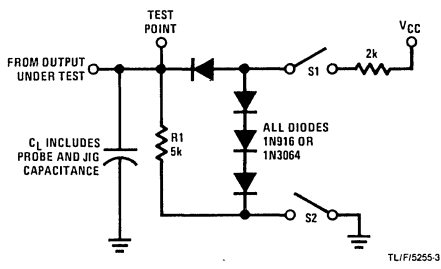


Switching Characteristics $V_{CC} = 5V, T_A = 25^\circ C$

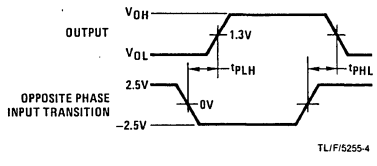
Parameter	Conditions	DS26LS32/DS26LS33			DS26LS32A/DS26LS33A			Units
		Min	Typ	Max	Min	Typ	Max	
t_{PLH} t_{PHL}	Input to Output		17	25		23	35	ns
t_{LZ} t_{HZ}	ENABLE to Output	$C_L = 15 \text{ pF}$	17	25		23	35	ns
t_{LZ} t_{HZ}	ENABLE to Output	$C_L = 5 \text{ pF}$	20	30		15	22	ns
t_{ZL} t_{ZH}	ENABLE to Output	$C_L = 15 \text{ pF}$	15	22		20	25	ns
t_{ZL} t_{ZH}	ENABLE to Output	$C_L = 15 \text{ pF}$	15	22		14	22	ns
t_{ZL} t_{ZH}	ENABLE to Output	$C_L = 15 \text{ pF}$	15	22		15	22	ns

AC Test Circuit and Switching Time Waveforms

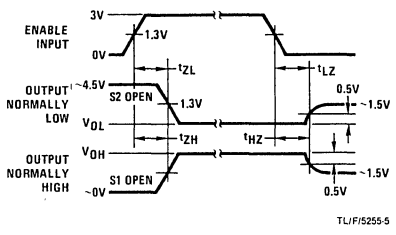
Load Test Circuit for TRI-STATE Outputs



Propagation Delay (Notes 1 and 3)



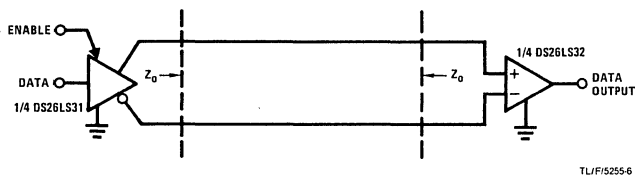
Enable and Disable Times (Notes 2 and 3)



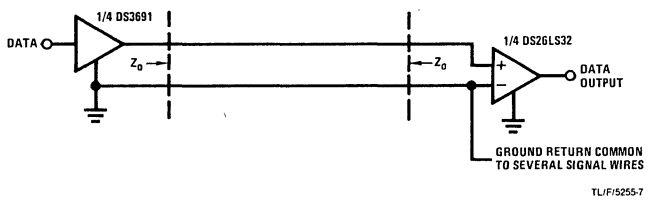
- Note 1:** Diagram shown for ENABLE low.
- Note 2:** S1 and S2 of load circuit are closed except where shown.
- Note 3:** Pulse generator for all pulses: Rate $\leq 1.0 \text{ MHz}$; $Z_O = 50\Omega$; $t_r \leq 15 \text{ ns}$; $t_f \leq 6.0 \text{ ns}$.

Typical Applications

Two-Wire Balanced Systems, RS-422



Single Wire with Common Ground Unbalanced Systems, RS-423



DS3486 Quad RS-422, RS-423 Line Receiver

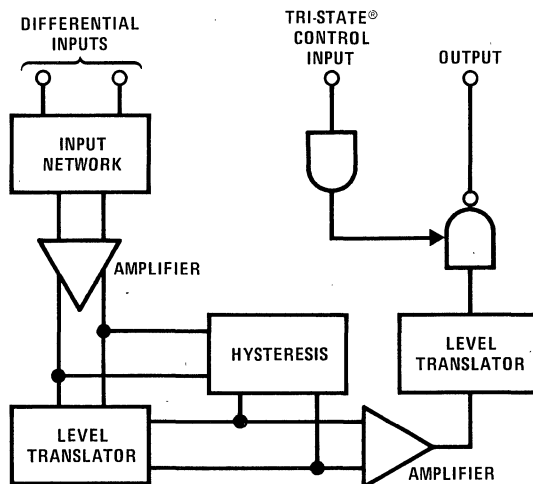
General Description

National's quad RS-422, RS-423 receiver features four independent receiver chains which comply with EIA Standards for the electrical characteristics of balanced/unbalanced voltage digital interface circuits. Receiver outputs are 74LS compatible, TRI-STATE® structures which are forced to a high impedance state when the appropriate output control pin reaches a logic zero condition. A PNP device buffers each output control pin to assure minimum loading for either logic one or logic zero inputs. In addition, each receiver chain has internal hysteresis circuitry to improve noise margin and discourage output instability for slowly changing input waveforms.

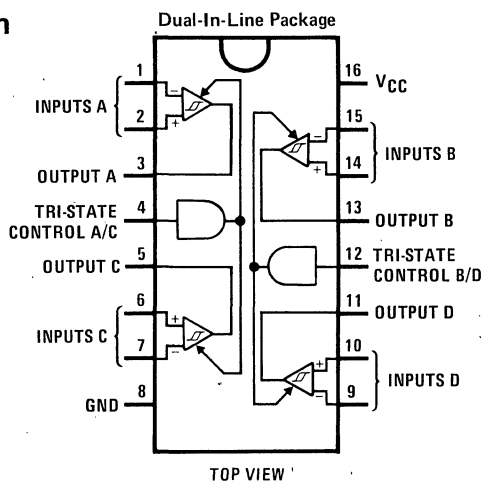
Features

- Four independent receiver chains
- TRI-STATE outputs
- High impedance output control inputs (PIA compatible)
- Internal hysteresis – 140 mV (typ)
- Fast propagation times – 18 ns (typ)
- TTL compatible
- Single 5V supply voltage
- Pin compatible and interchangeable with MC3486

Block Diagram



Connection Diagram



Order Number DS3486J or DS3486N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Power Supply Voltage, V_{CC}	8 V
Input Common-Mode Voltage, V_{ICM}	± 25 V
Input Differential Voltage, V_{ID}	± 25 V
TRI-STATE Control Input Voltage, V_I	8 V
Output Sink Current, I_O	50 mA
Storage Temperature, T_{STG}	-65°C to $+150^{\circ}\text{C}$
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW

*Derate cavity package $9.6\text{ mW}/^{\circ}\text{C}$ above 25°C ; derate molded package $10.2\text{ mW}/^{\circ}\text{C}$ above 25°C .

Operating Conditions

	MIN	MAX	UNITS
Power Supply Voltage, V_{CC}	4.75	5.25	V
Operating Temperature, T_A	0	70	$^{\circ}\text{C}$
Input Common-Mode Voltage Range, V_{ICR}	-7.0	7.0	V

Electrical Characteristics

(Unless otherwise noted, minimum and maximum limits apply over recommended temperature and power supply voltage ranges. Typical values are for $T_A = 25^{\circ}\text{C}$, $V_{CC} = 5\text{V}$ and $V_{IC} = 0\text{V}$. See Note 2.)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{IH}	Input Voltage – High Logic State (TRI-STATE Control)	2.0			V
V_{IL}	Input Voltage – Low Logic State (TRI-STATE Control)			0.8	V
$V_{TH(D)}$	Differential Input Threshold Voltage $-7\text{V} \leq V_{IC} \leq 7\text{V}$, V_{IH} TRI-STATE = 2V $I_O = 0.4\text{ mA}$, $V_{OH} \geq 2.7\text{V}$		0.070	0.2	V
			0.070	-0.2	V
					V
$I_{IB(D)}$	Input Bias Current $V_{CC} = 0\text{V}$ or 5.25V , Other Inputs at 0V				
		$V_I = -10\text{V}$		-3.25	mA
		$V_I = -3\text{V}$		-1.50	mA
		$V_I = 3\text{V}$		1.50	mA
		$V_I = 10\text{V}$		3.25	mA
Input Balance	$-7\text{V} \leq V_{IC} \leq 7\text{V}$, $V_{IH(3C)} = 2\text{V}$, (Note 4)				
		$I_O = 0.4\text{ mA}$, $V_{ID} = 0.4\text{V}$	2.7		V
		$I_O = 8\text{ mA}$, $V_{ID} = -0.4\text{V}$		0.5	V
I_{OZ}	Output TRI-STATE Leakage Current $V_{I(D)} = 3\text{V}$, $V_{IL} = 0.8\text{V}$, $V_{OL} = 0.5\text{V}$ $V_{I(D)} = -3\text{V}$, $V_{IL} = 0.8\text{V}$, $V_{OH} = 2.7\text{V}$			-40	μA
				40	μA
I_{OS}	Output Short-Circuit Current $V_{I(D)} = 3\text{V}$, V_{IH} TRI-STATE = 2V, $V_O \approx 0$, (Note 3)	-15		-100	mA
I_{IL}	Input Current – Low Logic State (TRI-STATE Control)			-100	μA
I_{IH}	Input Current – High Logic State (TRI-STATE Control)			20	μA
				100	μA
V_{IC}	Input Clamp Diode Voltage (TRI-STATE Control)			-1.5	V
I_{CC}	Power Supply Current All Inputs $V_{IL} = 0\text{V}$			85	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All currents into device pins are shown as positive, out of device pins are negative. All voltages referenced to ground unless otherwise noted.

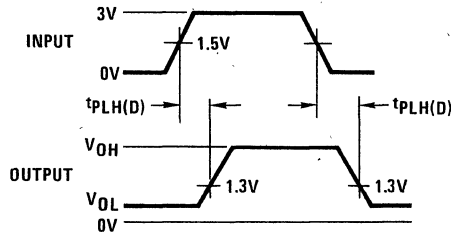
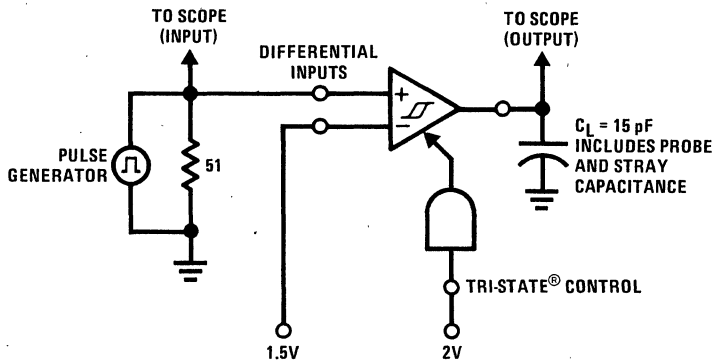
Note 3: Only one output at a time should be shorted.

Note 4: Refer to EIA RS-422/3 for exact conditions.

Switching Characteristics (Unless otherwise noted, $V_{CC} = 5V$ and $T_A = 25^\circ C$.)

PARAMETER		MIN	TYP	MAX	UNITS
Propagation Delay Time – Differential Inputs to Output					
$t_{PHL(D)}$	Output High to Low		19	35	ns
$t_{PLH(D)}$	Output Low to High		19	30	ns
Propagation Delay Time – TRI-STATE Control to Output					
t_{PLZ}	Output Low to TRI-STATE		23	35	ns
t_{PHZ}	Output High to TRI-STATE		25	35	ns
t_{PZH}	Output TRI-STATE to High		18	30	ns
t_{PZL}	Output TRI-STATE to Low		20	30	ns

AC Test Circuits and Switching Time Waveforms



Input pulse characteristics:
 $t_{TLH} = t_{THL} = 6\text{ ns}$ (10% to 90%)
 PRR = 1 MHz, 50% duty cycle

FIGURE 1. Propagation Delay Differential Input to Output

AC Test Circuits and Switching Time Waveforms (Continued)

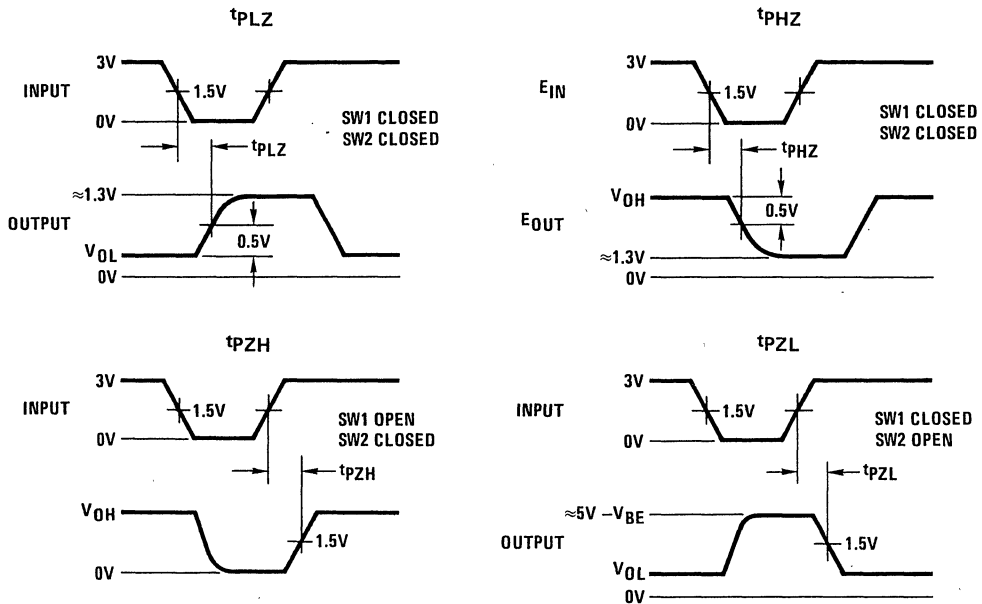
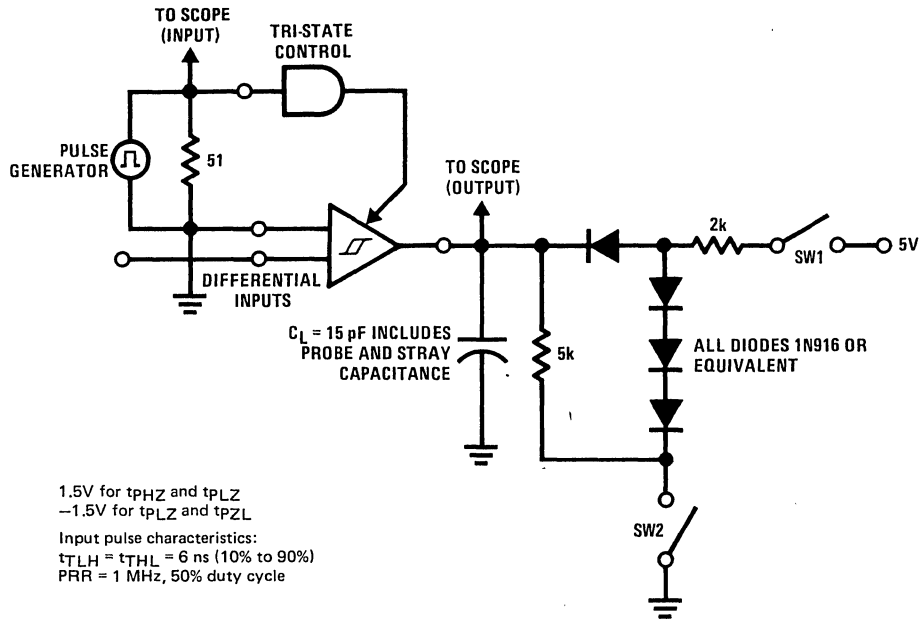


FIGURE 2. Propagation Delay TRI-STATE Control Input to Output

DS3587/DS3487 Quad TRI-STATE® Line Driver

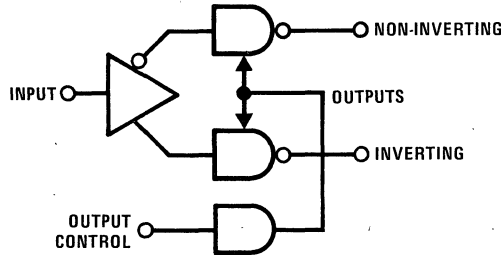
General Description

National's quad RS-422 driver features four independent driver chains which comply with EIA Standards for the electrical characteristics of balanced voltage digital interface circuits. The outputs are TRI-STATE® structures which are forced to a high impedance state when the appropriate output control pin reaches a logic zero condition. All input pins are PNP buffered to minimize input loading for either logic one or logic zero inputs. In addition, internal circuitry assures a high impedance output state during the transition between power up and power down.

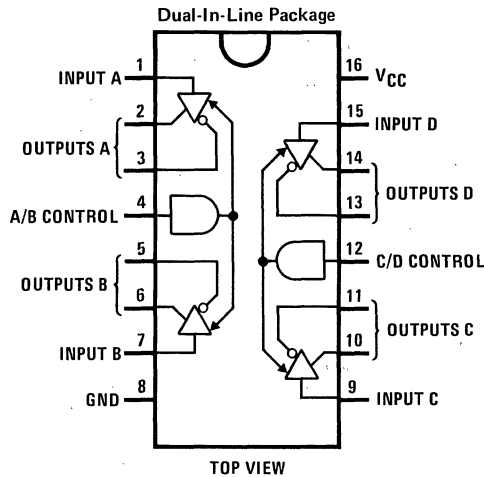
Features

- Four independent driver chains
- TRI-STATE outputs
- PNP high impedance inputs (PIA compatible)
- Power up/down protection
- Fast propagation times (typ 10 ns)
- TTL compatible
- Single 5V supply voltage
- Output rise and fall times less than 20 ns (typ 10 ns)
- Pin compatible with MC3487
- Output skew — 2 ns typ

Block Diagram



Connection Diagram



Order Number DS3587J, DS3487J or DS3487N
See NS Package J16A or N16A

Truth Table

INPUT	CONTROL INPUT	NON-INVERTER OUTPUT	INVERTER OUTPUT
H	H	H	L
L	H	L	H
X	L	Z	Z

L = Low logic state
H = High logic state
X = Irrelevant
Z = TRI-STATE (high impedance)

Absolute Maximum Ratings (Note 1)

Supply Voltage	8V
Input Voltage	5.5V
Storage Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS3587	4.5	5.5	V
DS3487	4.75	5.25	V
Temperature (T _A)			
DS3587	-55	+125	°C
DS3487	0	70	°C

Electrical Characteristics (Notes 2, 3, 4 and 5)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IL}	Input Low Voltage			0.8	V	
V _{IH}	Input High Voltage	2.0			V	
I _{IL}	Input Low Current	V _{IL} = 0.5V		-200	μA	
I _{IH}	Input High Current	V _{IH} = 2.7V		50	μA	
		V _{IH} = 5.5V		100	μA	
V _{CL}	Input Clamp Voltage	I _{CL} = -18 mA		-1.5	V	
V _{OL}	Output Low Voltage	I _{OL} = 48 mA		0.5	V	
V _{OH}	Output High Voltage	I _{OH} = -20 mA		2.5	V	
I _{OS}	Output Short-Circuit Current	-40		-140	mA	
I _{OZ}	Output Leakage Current (TRI-STATE)	V _O = 0.5V		-100	μA	
		V _O = 5.5V		100	μA	
I _{OFF}	Output Leakage Current Power OFF	V _{CC} = 0		100	μA	
		V _O = -0.25V		-100	μA	
V _{OS} - \bar{V} _{OS}	Difference in Output Offset Voltage			0.4	V	
V _T	Differential Output Voltage	2.0			V	
V _T - \bar{V} _T	Difference in Differential Output Voltage			0.4	V	
I _{CC}	Power Supply Current	Active		50	80	mA
		TRI-STATE		35	60	mA

Switching Characteristics V_{CC} = 5V, T_A = 25°C

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{PHL}	Input to Output		10	15	ns
t _{PLH}	Input to Output		10	15	ns
t _{THL}	Differential Fall Time		10	15	ns
t _{TLH}	Differential Rise Time		10	15	ns
t _{PHZ}	Enable to Output	R _L = 200Ω, C _L = 50 pF	17	25	ns
t _{PLZ}	Enable to Output	R _L = 200Ω, C _L = 50 pF	15	25	ns
t _{PZH}	Enable to Output	R _L = ∞, C _L = 50 pF, S1 Open	11	25	ns
t _{PZL}	Enable to Output	R _L = 200Ω, C _L = 50 pF, S2 Open	15	25	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C range for the DS3487. All typicals are given for V_{CC} = 5V and T_A = 25°C.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

Note 5: Symbols and definitions correspond to EIA RS-422, where applicable.

AC Test Circuits and Switching Time Waveforms

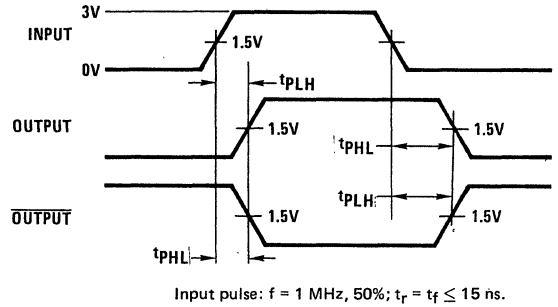
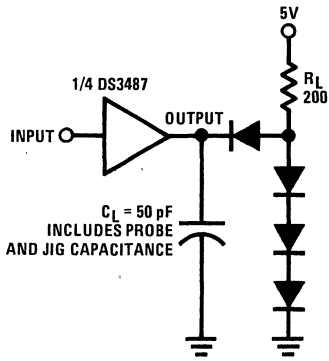
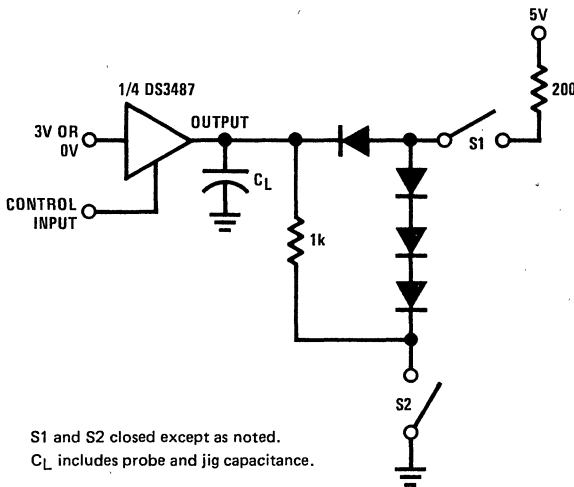


FIGURE 1. Propagation Delays



S1 and S2 closed except as noted.
 C_L includes probe and jig capacitance.

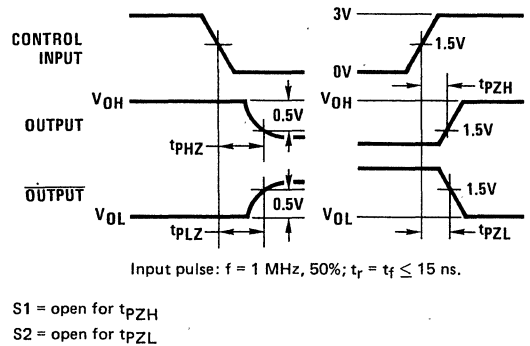


FIGURE 2. TRI-STATE Enable and Disable Delays

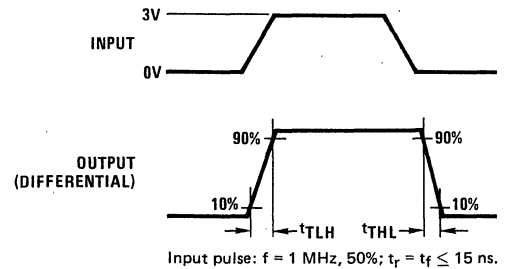
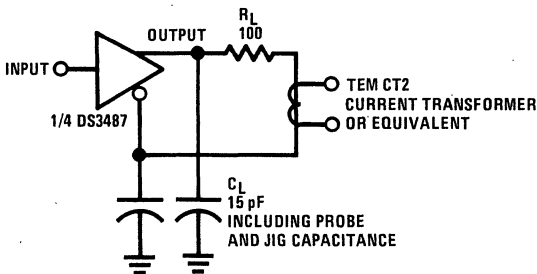


FIGURE 3. Differential Rise and Fall Times

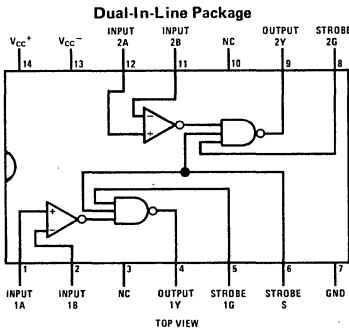
**DS1603/DS3603, DS55107/DS75107, DS55108/DS75108,
DS75207, DS75208 Dual Line Receivers**
General Description

The eight products described herein are TTL compatible dual high speed circuits intended for sensing in a broad range of system applications. While the primary usage will be for line receivers or MOS sensing, any of the products may effectively be used as voltage comparators, level translators, window detectors, transducer preamplifiers, and in other sensing applications. As digital line receivers the products are applicable with the SN55109/SN75109 and SN55110/SN75110 companion drivers, or may be used in other balanced or unbalanced party-line data transmission systems. The improved input sensitivity and delay specifications of the DS75207 and DS75208 make them ideal for sensing high performance MOS memories as well as high sensitivity line receivers and voltage comparators. TRI-STATE® products enhance based organizations.

Input protection diodes are incorporated in series with the collectors of the differential input stage. These diodes are useful in certain applications that have multiple V_{CC+} supplies or V_{CC+} supplies that are turned off.

Features

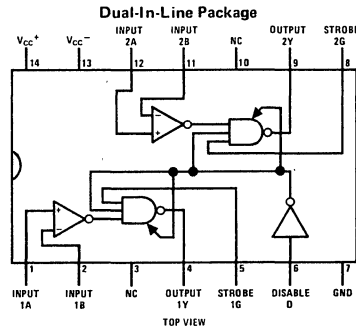
- Diode protected input stage for power "OFF" condition
- 17 ns typ high speed
- TTL compatible
- ± 10 mV or ± 25 mV input sensitivity
- $\pm 3V$ input common-mode range
- High input impedance with normal V_{CC} , or $V_{CC} = 0V$
- Strobes for channel selection
- TRI-STATE outputs for high speed buses
- Dual circuits
- Sensitivity gntd. over full common-mode range
- Logic input clamp diodes—meets both "A" and "B" version specifications
- $\pm 5V$ standard supply voltages

Connection Diagrams


**Order Number DS55107J, DS75107J,
DS55108J, DS75108J, DS75207J
or DS75208J**

See NS Package J14A

**Order Number DS75107N, DS75108N,
DS75207N or DS75208N**
See NS Package N14A



Order Number DS1603J or DS3603J
See NS Package J14A

Order Number DS3603N
See NS Package N14A

Product Selection Guide

TEMPERATURE→ PACKAGE→ INPUT SENSITIVITY→ OUTPUT LOGIC↓	$-55^{\circ}C \leq T_A \leq +125^{\circ}C$		$0^{\circ}C \leq T_A \leq +70^{\circ}C$	
	CAVITY DIP		CAVITY OR MOLDED DIP	
	± 25 mV		± 25 mV	± 10 mV
TTL Active Pull-up	DS55107	DS75107	DS75207	
TTL Open Collector	DS55108	DS75108	DS75208	
TTL TRI-STATE	DS1603	DS3603	DS3604	

**DS16/3603, 55/75107,
55/75108, 75207, 75208**



Absolute Maximum Ratings (Notes 1, 2 and 3)

Supply Voltage, V_{CC}^+	7V	Maximum Power Dissipation* at 25°C	
Supply Voltage, V_{CC}^-	-7V	Cavity Package	1308 mW
Differential Input Voltage	±6V	Molded Package	1207 mW
Common Mode Input Voltage	±5V	Lead Temperature (Soldering, 10 sec)	300°C
Strobe Input Voltage	5.5V		
Storage Temperature Range	-65°C to +150°C	*Derate cavity package 8.7 mW/°C above 25°C; derate molded package 9.7 mW/°C above 25°C.	

Operating Conditions

	DS55107, DS55108, DS1603			DS75107, DS75207 DS75108, DS75208 DS3603		
	MIN	NOM	MAX	MIN	NOM	MAX
Supply Voltage V_{CC}^+	4.5V	5V	5.5V	4.75V	5V	5.25V
Supply Voltage V_{CC}^-	-4.5V	-5V	-5.5V	-4.75V	-5V	-5.25V
Operating Temperature Range	-55°C	to	+125°C	0°C	to	+70°C

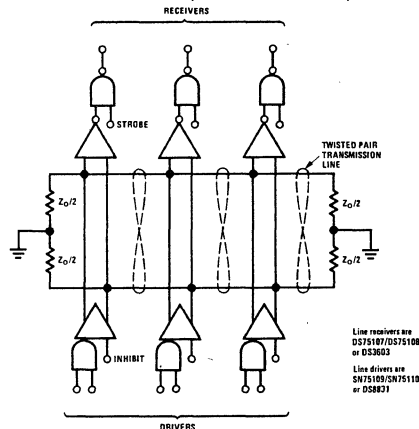
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS1603, DS55107 and DS55108 and across the 0°C to +70°C range for the DS3603, DS75107, DS75108. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5\text{V}$.

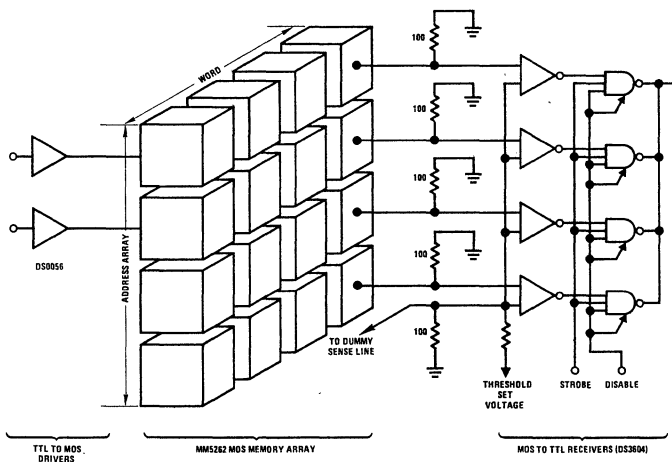
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Typical Applications

Line Receiver Used in a Party-Line or Data-Bus System

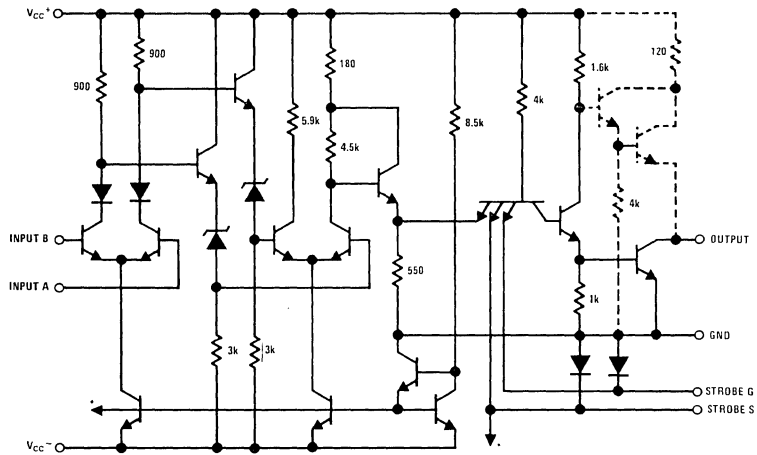


Line Receiver Used in MOS Memory System



Schematic Diagrams

DS55107/DS75107, DS75207
DS55108/DS75108, DS75208

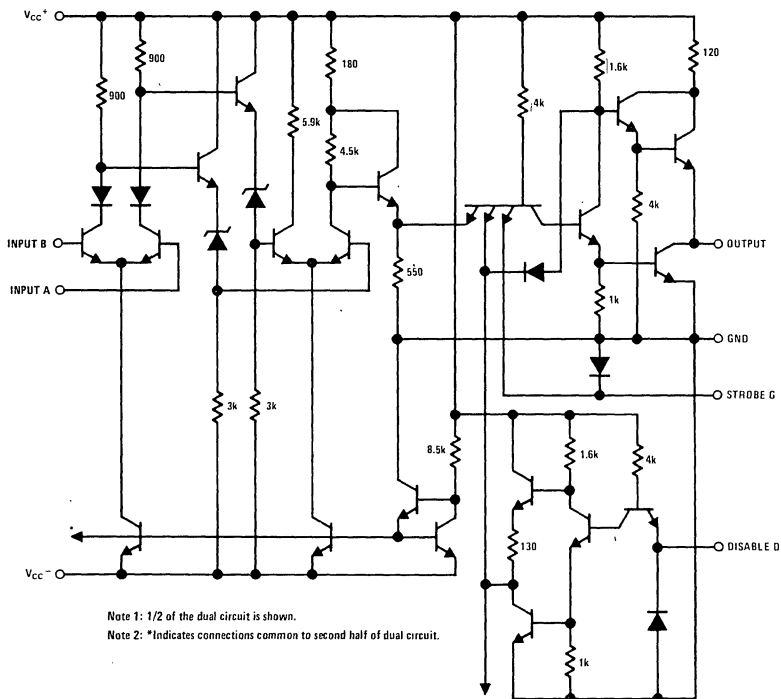


Note 1: 1/2 of the dual circuit is shown.

Note 2: *Indicates connections common to second half of dual circuit.

Note 3: Components shown with dash lines are applicable to the DS55107, DS75107 and DS75207 only.

DS1603/DS3603



Note 1: 1/2 of the dual circuit is shown.

Note 2: *Indicates connections common to second half of dual circuit.

DS16/3603, 55/75107,
55/75108, 75207, 75208



DS55107/DS75107, DS55108/DS75108

Electrical Characteristics ($T_{MIN} \leq T_A \leq T_{MAX}$)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
I_{IH}	High Level Input Current Into A1, B1, A2 or B2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{ID} = 0.5V, V_{IC} = -3V \text{ to } 3V$			30	75	μA
I_{IL}	Low Level Input Current Into A1, B1, A2 or B2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{ID} = -2V, V_{IC} = -3V \text{ to } 3V$				-10	μA
I_{IH}	High Level Input Current Into G1 or G2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}$	$V_{IH(S)} = 2.4V$			40	μA
			$V_{IH(S)} = \text{Max } V_{CC+}$			1	mA
I_{IL}	Low Level Input Current Into G1 or G2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{IL(S)} = 0.4V$				-1.6	mA
I_{IH}	High Level Input Current Into S	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}$	$V_{IH(S)} = 2.4V$			80	μA
			$V_{IH(S)} = \text{Max } V_{CC+}$			2	mA
I_{IL}	Low Level Input Current Into S	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{IL(S)} = 0.4V$				-3.2	mA
V_{OH}	High Level Output Voltage	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min}, I_{LOAD} = -400\mu A, V_{ID} = 25 \text{ mV}, V_{IC} = -3V \text{ to } 3V, \text{ (Note 3)}$		2.4			V
V_{OL}	Low Level Output Voltage	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min}, I_{SINK} = 16 \text{ mA}, V_{ID} = -25 \text{ mV}, V_{IC} = -3V \text{ to } 3V$				0.4	V
I_{OH}	High Level Output Current	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min}, V_{OH} = \text{Max } V_{CC+}, \text{ (Note 4)}$				250	μA
I_{OS}	Short Circuit Output Current	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, \text{ (Notes 2 and 3)}$		-18		-70	mA
I_{CCH+}	High Logic Level Supply Current From V_{CC}	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{ID} = 25 \text{ mV}, T_A = 25^\circ C$			18	30	mA
I_{CCH-}	High Logic Level Supply Current From V_{CC}	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{ID} = 25 \text{ mV}, T_A = 25^\circ C$			-8.4	-15	mA
V_I	Input Clamp Voltage on G or S	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min}, I_{IN} = -12 \text{ mA}, T_A = 25^\circ C$			-1	-1.5	V

Switching Characteristics ($V_{CC+} = 5V, V_{CC-} = -5V, T_A = 25^\circ C$)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
$t_{PLH(D)}$	Propagation Delay Time, Low to High Level, From Differential Inputs A and B to Output	$R_L = 390\Omega, C_L = 50 \text{ pF}, \text{ (Note 1)}$	(Note 3)		17	25	ns
			(Note 4)		19	25	ns
$t_{PHL(D)}$	Propagation Delay Time, High to Low Level, From Differential Inputs A and B to Output	$R_L = 390\Omega, C_L = 50 \text{ pF}, \text{ (Note 1)}$	(Note 3)		17	25	ns
			(Note 4)		19	25	ns
$t_{PLH(S)}$	Propagation Delay Time, Low to High Level, From Strobe Input G or S to Output	$R_L = 390\Omega, C_L = 50 \text{ pF}$	(Note 3)		10	15	ns
			(Note 4)		13	20	ns
$t_{PHL(S)}$	Propagation Delay Time, High to Low Level, From Strobe Input G or S to Output	$R_L = 390\Omega, C_L = 50 \text{ pF}$	(Note 3)		8	15	ns
			(Note 4)		13	20	ns

Note 1: Differential input is +100 mV to -100 mV pulse. Delays read from 0 mV on input to 1.5V on output.

Note 2: Only one output at a time should be shorted.

Note 3: DS55107/DS75107 only.

Note 4: DS55108/DS75108 only.

DS75207, DS75208

Electrical Characteristics ($0^{\circ}\text{C} \leq T_A \leq +70^{\circ}\text{C}$)

DS16/3603, 55/75107,
55/75108, 75207, 75208



PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
I_{IH}	High Level Input Current Into A1, B1, A2 or B2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{ID} = 0.5\text{V}, V_{IC} = -3\text{V to } 3\text{V}$		30	75	μA
I_{IL}	Low Level Input Current Into A1, B1, A2 or B2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{ID} = -2\text{V}, V_{IC} = -3\text{V to } 3\text{V}$			-10	μA
I_{IH}	High Level Input Current Into G1 or G2	$V_{CC+} = \text{Max}, V_{IC(S)} = 2.4\text{V}$			40	μA
		$V_{CC-} = \text{Max}, V_{IC(S)} = \text{Max } V_{CC+}$			1	mA
I_{IL}	Low Level Input Current Into G1 or G2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{IL(S)} = 0.4\text{V}$			-1.6	mA
I_{IH}	High Level Input Current Into S	$V_{CC+} = \text{Max}, V_{IC(S)} = 2.4\text{V}$			80	μA
		$V_{CC-} = \text{Max}, V_{IC(S)} = \text{Max } V_{CC+}$			2	mA
I_{IL}	Low Level Input Current Into S	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{IL(S)} = 0.4\text{V}$			-3.2	mA
V_{OH}	High Level Output Voltage	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min}, I_{LOAD} = -400\mu\text{A}, V_{ID} = 10\text{ mV}, V_{IC} = -3\text{V to } 3\text{V}, (\text{Note } 3)$	2.4			V
V_{OL}	Low Level Output Voltage	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min}, I_{SINK} = 16\text{ mA}, V_{ID} = -10\text{ mV}, V_{IC} = -3\text{V to } 3\text{V}$			0.4	V
I_{OH}	High Level Output Current	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min}, V_{OH} = \text{Max } V_{CC+}, (\text{Note } 4)$			250	μA
I_{OS}	Short Circuit Output Current	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max} (\text{Notes } 2, 3 \text{ and } 4)$	-18		-70	mA
I_{CCH+}	High Logic Level Supply Current From V_{CC}	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{ID} = 10\text{ mV}, T_A = 25^{\circ}\text{C}$		18	30	mA
I_{CCH-}	High Logic Level Supply Current From V_{CC}	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max}, V_{ID} = 10\text{ mV}, T_A = 25^{\circ}\text{C}$		-8.4	-15	mA
V_I	Input Clamp Voltage on G or S	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min}, I_{IN} = -12\text{ mA}, T_A = 25^{\circ}\text{C}$		-1	-1.5	V

Switching Characteristics ($V_{CC+} = 5\text{V}, V_{CC-} = -5\text{V}, T_A = 25^{\circ}\text{C}$)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
$t_{PLH(D)}$	Propagation Delay Time, Low-to-High Level, From Differential Inputs A and B to Output	$R_L = 470\Omega, C_L = 15\text{ pF}, (\text{Note } 1)$			35	ns
$t_{PHL(D)}$	Propagation Delay Time, High-to-Low Level, From Differential Inputs A and B to Output	$R_L = 470\Omega, C_L = 15\text{ pF}, (\text{Note } 1)$			20	ns
$t_{PLH(S)}$	Propagation Delay Time, Low-to-High Level, From Strobe Input G or S to Output	$R_L = 470\Omega, C_L = 15\text{ pF}$			17	ns
$t_{PHL(S)}$	Propagation Delay Time, High-to-Low Level, From Strobe Input G or S to Output	$R_L = 470\Omega, C_L = 15\text{ pF}$			17	ns

Note 1: Differential input is +10 mV to -30 mV pulse. Delays read from 0 mV on input to 1.5V on output.

Note 2: Only one output at a time should be shorted.

Note 3: DS75207 only.

Note 4: DS75208 only.

DS1603/DS3603

Electrical Characteristics ($T_{MIN} \leq T_A \leq T_{MAX}$)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
I_{IH}	High Level Input Current Into A1, B1, A2 or B2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max},$ $V_{ID} = 0.5V, V_{IC} = -3V \text{ to } 3V$		30	75	μA
I_{IL}	Low Level Input Current Into A1, B1, A2 or B2	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max},$ $V_{ID} = -2V, V_{IC} = -3V \text{ to } 3V$			-10	μA
I_{IH}	High Level Input Current Into G1, G2 or D	$V_{CC+} = \text{Max},$			40	μA
		$V_{CC-} = \text{Max}$	$V_{IH(S)} = 2.4V$		1	mA
I_{IL}	Low Level Input Current Into D	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max},$			-1.6	mA
		$V_{IL(D)} = 0.4V$				
I_{IL}	Low Level Input Current Into G1 or G2	$V_{CC+} = \text{Max},$	$V_{IH(D)} = 2V$		-40	μA
		$V_{CC-} = \text{Max},$ $V_{IL(G)} = 0.4V$	$V_{IL(D)} = 0.8V$		-1.6	mA
V_{OH}	High Level Output Voltage	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min},$ $I_{LOAD} = -2 \text{ mA}, V_{ID} = 25 \text{ mV}$ $V_{IL(D)} = 0.8V, V_{IC} = -3V \text{ to } 3V$	2.4			V
V_{OL}	Low Level Output Voltage	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min},$ $I_{SINK} = 16 \text{ mA}, V_{ID} = -25 \text{ mV},$ $V_{IL(D)} = 0.8V, V_{IC} = -3V \text{ to } 3V$			0.4	V
I_{OD}	Output Disable Current	$V_{CC+} = \text{Max},$ $V_{CC-} = \text{Max}$	$V_{OUT} = 2.4V$		40	μA
		$V_{IH(D)} = 2V$	$V_{OUT} = 0.4V$		-40	μA
I_{OS}	Short Circuit Output Current	$V_{CC+} = \text{Max}, V_{IL(D)} = 0.8V,$ $V_{CC-} = \text{Max}, (\text{Note } 2)$	-18		-70	mA
I_{CCH+}	High Logic Level Supply Current From V_{CC+}	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max},$ $V_{ID} = 25 \text{ mV}, T_A = 25^\circ C$		28	40	mA
I_{CCH-}	High Logic Level Supply Current From V_{CC-}	$V_{CC+} = \text{Max}, V_{CC-} = \text{Max},$ $V_{ID} = 25 \text{ mV}, T_A = 25^\circ C$		-8.4	-15	mA
V_I	Input Clamp Voltage on G or D	$V_{CC+} = \text{Min}, V_{CC-} = \text{Min},$ $I_{IN} = -12 \text{ mA}, T_A = 25^\circ C$		-1	-1.5	V

Switching Characteristics ($V_{CC+} = 5V, V_{CC-} = -5V, T_A = 25^\circ C$)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
$t_{PLH(D)}$	Propagation Delay Time, Low-to-High Level, From Differential Inputs A and B to Output	$R_L = 390\Omega, C_L = 50 \text{ pF}, (\text{Note } 1)$		17	25	ns
$t_{PHL(D)}$	Propagation Delay Time, High-to-Low Level, From Differential Inputs A and B to Output	$R_L = 390\Omega, C_L = 50 \text{ pF}, (\text{Note } 1)$		17	25	ns
$t_{PLH(S)}$	Propagation Delay Time, Low-to-High Level, From Strobe Input G to Output	$R_L = 390\Omega, C_L = 50 \text{ pF}$		10	15	ns
$t_{PHL(S)}$	Propagation Delay Time, High-to-Low Level, From Strobe Input G to Output	$R_L = 390\Omega, C_L = 50 \text{ pF}$		8	15	ns
t_{1H}	Disable Low-to-High to Output High to Off	$R_L = 390\Omega, C_L = 5 \text{ pF}$			20	ns
t_{0H}	Disable Low-to-High to Output Low to Off	$R_L = 390\Omega, C_L = 5 \text{ pF}$			30	ns
t_{H1}	Disable High-to-Low to Output Off to High	$R_L = 1k \text{ to } 0V, C_L = 50 \text{ pF}$			25	ns
t_{H0}	Disable High-to-Low to Output Off to Low	$R_L = 390\Omega, C_L = 50 \text{ pF}$			25	ns

Note 1: Differential input is +100 mV to -100 mV pulse. Delays read from 0 mV on input to 1.5V on output.

Note 2: Only one output at a time should be shorted.

DS1650/DS3650, DS1652/DS3652
Quad Differential Line Receivers

General Description

The DS1650/DS3650 and DS1652/DS3652 are TTL compatible quad high speed circuits intended primarily for line receiver applications. Switching speeds have been enhanced over conventional line receivers by the use of Schottky technology, and TRI-STATE[®] strobing is incorporated offering a high impedance output state for bussed organizations.

The DS1650/DS3650 has active pull-up outputs and offers a TRI-STATE strobe, while the DS1652/DS3652 offers open collector outputs providing implied "AND" operation.

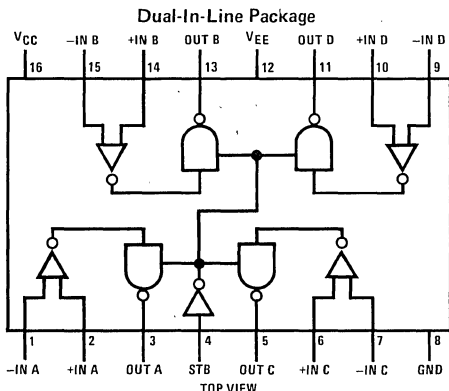
The DS1652/DS3652 can be used for address decoding as illustrated below. All outputs of the DS1652/DS3652 are tied together through a common resistor to 5V. In

this configuration the DS1652/DS3652 provides the "AND" function. All addresses have to be true before the output will go high. This scheme eliminates the need for an "AND" gate and enhances speed throughput for address decoding.

Features

- High speed
- TTL compatible
- Input sensitivity ± 25 mV
- TRI-STATE outputs for high speed busses
- Standard supply voltages ± 5 V
- Pin and function compatible with MC3450 and MC3452

Connection Diagram



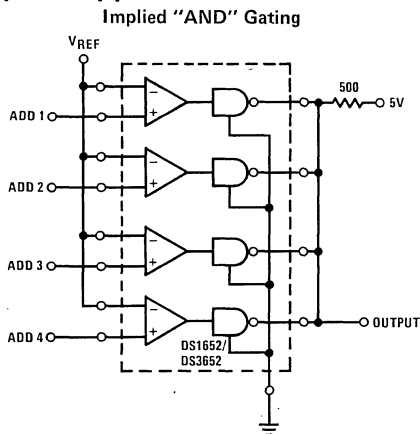
Order Number DS1650J, DS1652J,
DS3650J, DS3652J,
DS3650N or DS3652N
See NS Package J16A or N16A

Truth Table

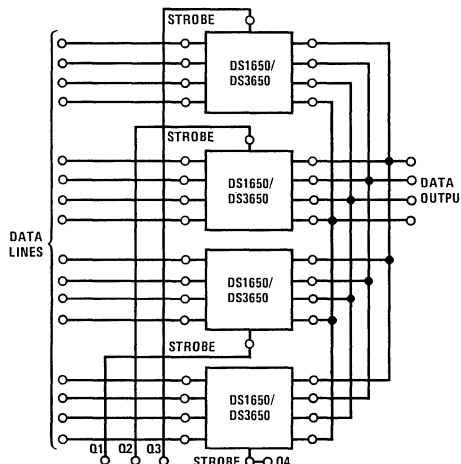
INPUT	STROBE	OUTPUT	
		DS1650/ DS3650	DS1652/ DS3652
$V_{ID} \geq 25$ mV	L	H	Open
	H	Open	Open
-25 mV $\leq V_{ID} \leq 25$ mV	L	X	X
	H	Open	Open
$V_{ID} \leq -25$ mV	L	L	L
	H	Open	Open

L = Low Logic State Open = TRI-STATE
H = High Logic State X = Indeterminate State

Typical Applications



Wired "OR" Data Selecting Using TRI-STATE Logic



Absolute Maximum Ratings (Note 1)

Power Supply Voltages	
V _{CC}	+7.0 V _{DC}
V _{EE}	-7.0 V _{DC}
Differential-Mode Input Signal Voltage	
Range, V _{IDR}	±6.0 V _{DC}
Common-Mode Input Voltage Range, V _{ICR}	
	±5.0 V _{DC}
Strobe Input Voltage, V _{I(S)}	
	5.5 V _{DC}
Storage Temperature Range	
	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	
	300°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V _{CC}			
DS1650, DS1652	4.5	5.5	V _{DC}
DS3650, DS3652	4.75	5.25	V _{DC}
Supply Voltage, V _{EE}			
DS1650, DS1652	-4.5	-5.5	V _{DC}
DS3650, DS3652	-4.75	-5.25	V _{DC}
Operating Temperature, T _A			
DS1650, DS1652	-55	+125	°C
DS3650, DS3652	0	+70	°C
Output Load Current, I _{OL}			
		16	mA
Differential-Mode Input Voltage Range, V _{IDR}			
	-5.0	+5.0	V _{DC}
Common-Mode Input Voltage Range, V _{ICR}			
	-3.0	+3.0	V _{DC}
Input Voltage Range (Any Input to GND), V _{IR}			
	-5.0	+3.0	V _{DC}

Electrical Characteristics

(V_{CC} = 5.0 V_{DC}, V_{EE} = -5.0 V_{DC}, Min ≤ T_A ≤ Max, unless otherwise noted) (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{IS} Input Sensitivity, (Note 5) (Common-Mode Voltage Range = -3V ≤ V _{IN} ≤ 3V)	Min ≤ V _{CC} ≤ Max Min ≥ V _{EE} ≥ Max			±25.0	mV
I _{IH(I)} High Level Input Current to Receiver Input	(Figure 5)			75	μA
I _{IL(I)} Low Level Input Current to Receiver Input	(Figure 6)			-10	μA
I _{IH(S)} High Level Input Current to Strobe Input	(Figure 3)	V _{IH(S)} = 2.4V, DS1650, DS1652		100	μA
		V _{IH(S)} = 2.4V, DS3650, DS3652		40	μA
		V _{IH(S)} = V _{CC}		1	mA
I _{IL(S)} Low Level Input Current to Strobe Input		V _{IH(S)} = 0.4V		-1.6	mA
V _{OH} High Level Output Voltage	(Figure 1)	DS1650, DS3650	2.4		V _{DC}
I _{CEX} High Level Output Leakage Current		DS1652, DS3652		250	μA
V _{OL} Low Level Output Voltage	(Figure 1)	DS3650, DS3652		0.45	V _{DC}
		DS1650, DS1652		0.50	
I _{OS} Short-Circuit Output Current (Note 4)	(Figure 4)	DS1650/DS3650	-18	-70	mA
I _{OFF} Output Disable Leakage Current	(Figure 7)	DS1650		100	μA
		DS3650		40	μA
I _{CCH} High Logic Level Supply Current from V _{CC}	(Figure 2)		45	60	mA
I _{EEH} High Logic Level Supply Current from V _{EE}	(Figure 2)		-17	-30	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C range for the DS3650, DS3652 and the -55°C to +125°C range for the DS1650, DS1652. All typical values are for T_A = 25°C, V_{CC} = 5V and V_{EE} = -5V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

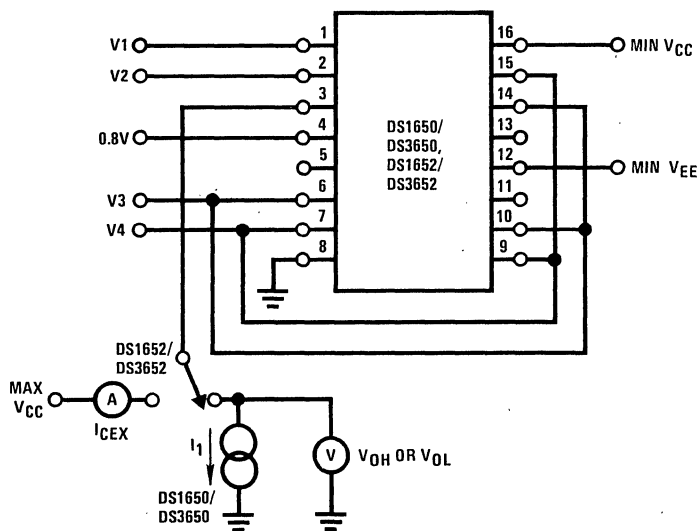
Note 4: Only one output at a time should be shorted.

Note 5: A parameter which is of primary concern when designing with line receivers is, what is the minimum differential input voltage required as the receiver input terminals to guarantee a given output logic state. This parameter is commonly referred to as threshold voltage. It is well known that design considerations of threshold voltage are plagued by input offset currents, bias currents, network source resistances, and voltage gain. As a design convenience, the DS1650, DS1652 and the DS3650, DS3652 are specified to a parameter called input sensitivity (V_{IS}). This parameter takes into consideration input offset currents and bias currents and guarantees a minimum input differential voltage to cause a given output logic state with respect to a maximum source impedance of 200Ω at each input.

Switching Characteristics ($V_{CC} = 5 V_{DC}$, $V_{EE} = -5 V_{DC}$, $T_A = 25^\circ C$ unless otherwise noted)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
t _{PHL(D)}	High-to-Low Logic Level Propagation Delay Time (Differential Inputs)	(Figure 8)	DS1650/DS3650		21	25	ns
			DS1652/DS3652		20	25	ns
t _{PLH(D)}	Low-to-High Logic Level Propagation Delay Time (Differential Inputs)		DS1650/DS3650		20	25	ns
			DS1652/DS3652		22	25	ns
t _{POH(S)}	TRI-STATE to High Logic Level Propagation Delay Time (Strobe)	(Figure 9)	DS1650/DS3650		16	21	ns
			DS1650/DS3650		7	18	ns
t _{POL(S)}	TRI-STATE to Low Logic Level Propagation Delay Time (Strobe)		DS1650/DS3650		19	27	ns
			DS1650/DS3650		14	29	ns
t _{PLO(S)}	Low Logic Level to TRI-STATE Propagation Delay Time (Strobe)		DS1650/DS3650		14	29	ns
t _{PHL(S)}	High-to-Low Logic Level Propagation Delay Time (Strobe)	(Figure 10)	DS1652/DS3652		16	25	ns
t _{PLH(S)}	Low-to-High Logic Level Propagation Delay Time (Strobe)		DS1652/DS3652		13	25	ns

Electrical Characteristic Test Circuits



	V1		V2		V3		V4		I ₁
	DS1650/DS3650	DS1652/DS3652	DS1650/DS3650	DS1652/DS1652	DS1650/DS1650	DS1652/DS1652	DS1650/DS1650	DS1652/DS1652	
V _{OH}	+2.975V -3.0V		+3.0V -2.975V		+3.0V GND		GND -3.0V		+0.4 mA +0.4 mA
I _{CEX}		+2.975V -3.0V		+3.0V -2.975V		+3.0V GND		GND -3.0V	
V _{OL}	+3.0V -2.975V	+3.0V -2.975V	+2.975V -3.0V	+2.975V -3.0V	GND -3.0V	GND -3.0V	+3.0V GND	+3.0V GND	-16 mA -16 mA

Channel A shown under test. Other channels are tested similarly.

FIGURE 1. I_{CEX}, V_{OH} and V_{OL}

Electrical Characteristic Test Circuits (Continued)

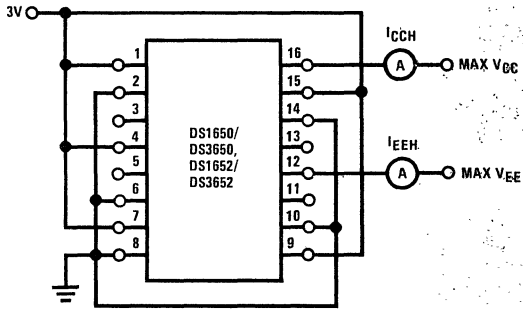


FIGURE 2. I_{CCH} and I_{EEH}

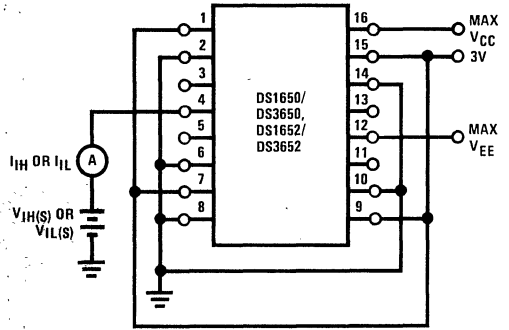
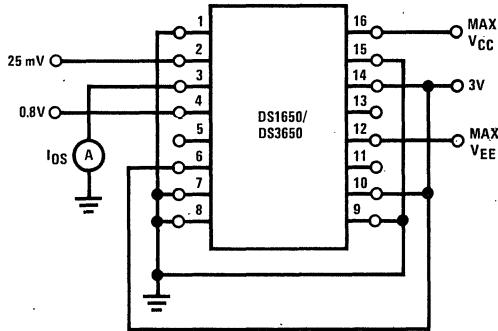
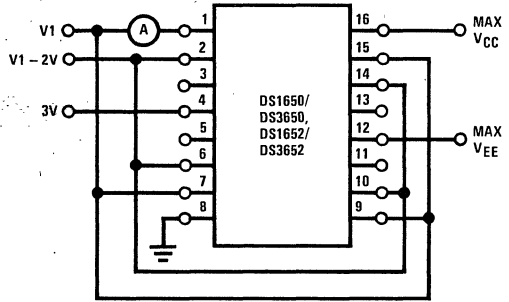


FIGURE 3. $I_{iH}(s)$ and $I_{iL}(s)$



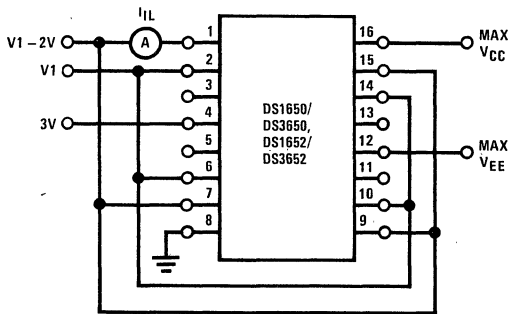
Note. Channel A shown under test, other channels are tested similarly. Only one output shorted at a time.

FIGURE 4. I_{OS}



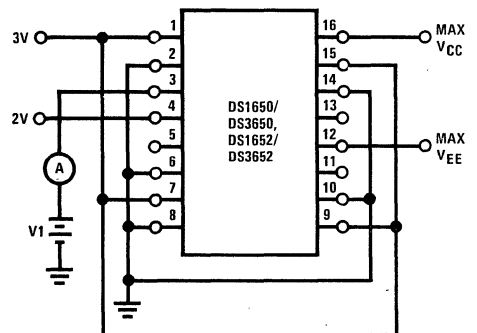
Note. Channel A(—) shown under test, other channels are tested similarly. Devices are tested with V_1 from 3V to -3V.

FIGURE 5. I_{iH}



Note. Channel A(—) shown under test, other channels are tested similarly. Devices are tested with V_1 from 3V to -3V.

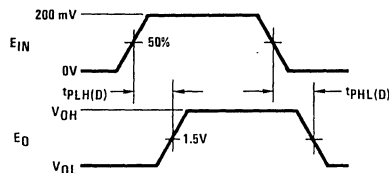
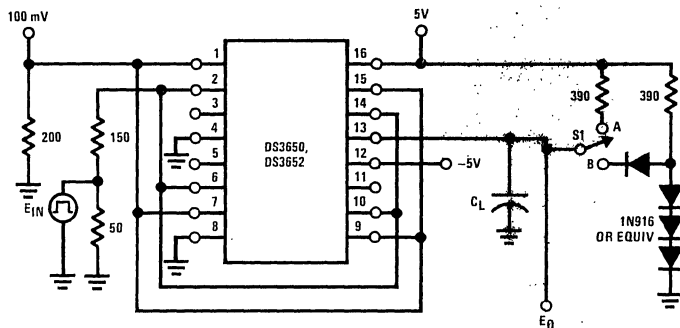
FIGURE 6. I_{iL}



Note. Output of Channel A shown under test, other outputs are tested similarly for $V_1 = 0.4V$ and $2.4V$.

FIGURE 7. I_{OFF}

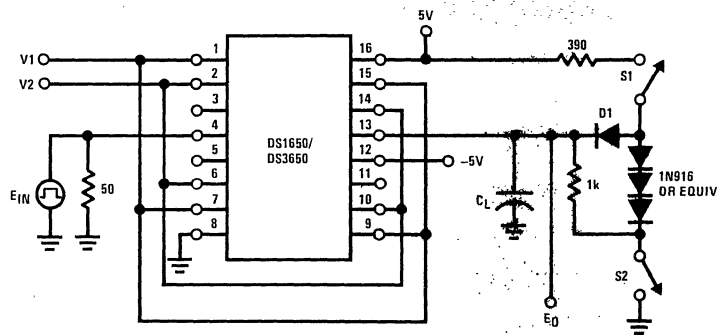
AC Test Circuits and Switching Time Waveforms



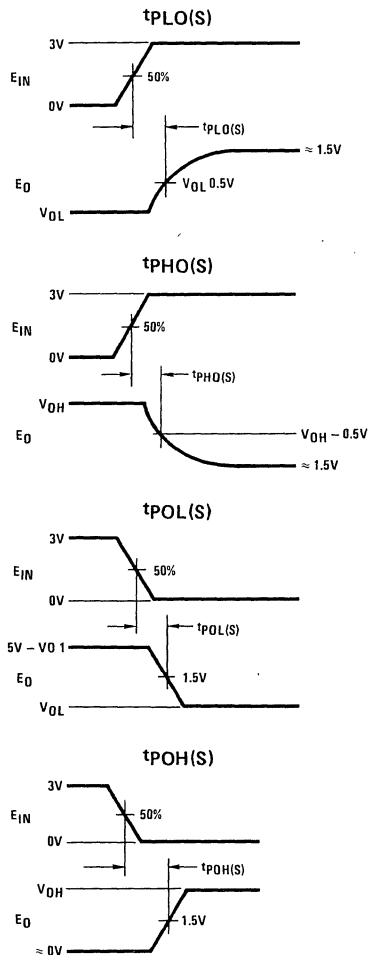
Note. Output of Channel B shown under test, other channels are tested similarly.
 S1 at "A" for DS1652/DS3652
 S1 at "B" for DS1650/DS3652
 $C_L = 15 \text{ pF}$ total for DS1652/DS3652
 $C_L = 50 \text{ pF}$ total for DS1650/DS3652

E_{IN} waveform characteristics:
 t_{TLH} and $t_{THL} \leq 10 \text{ ns}$ measured 10% to 90%
 PRR = 1 MHz
 Duty Cycle = 500 ns

FIGURE 8. Receiver Propagation Delay $t_{PLH(D)}$ and $t_{PHL(D)}$



Note. Output of Channel B shown under test, other channels are tested similarly.

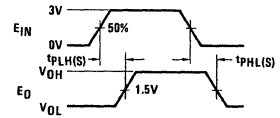
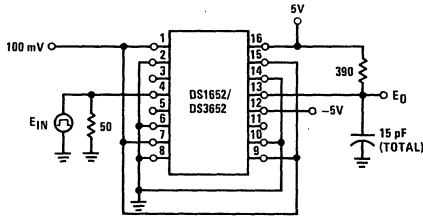


	V1	V2	S1	S2	C_L
$t_{PLO(S)}$	100 mV	GND	Closed	Closed	15 pF
$t_{POL(S)}$	100 mV	GND	Closed	Open	50 pF
$t_{PHO(S)}$	GND	100 mV	Closed	Closed	15 pF
$t_{POH(S)}$	GND	100 mV	Open	Closed	50 pF

C_L includes jig and probe capacitance.
 E_{IN} waveform characteristics: t_{TLH} and $t_{THL} \leq 10 \text{ ns}$ measured 10% to 90%
 PRR = 1 MHz
 Duty Cycle = 50%

FIGURE 9. Strobe Propagation Delay $t_{PLO(S)}$, $t_{POL(S)}$, $t_{PHO(S)}$ and $t_{POH(S)}$

AC Test Circuits and Switching Time Waveforms (Continued)

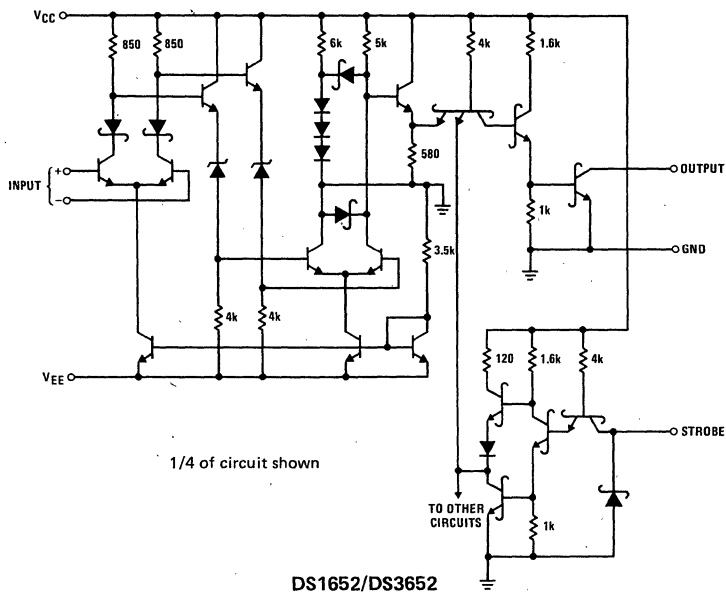
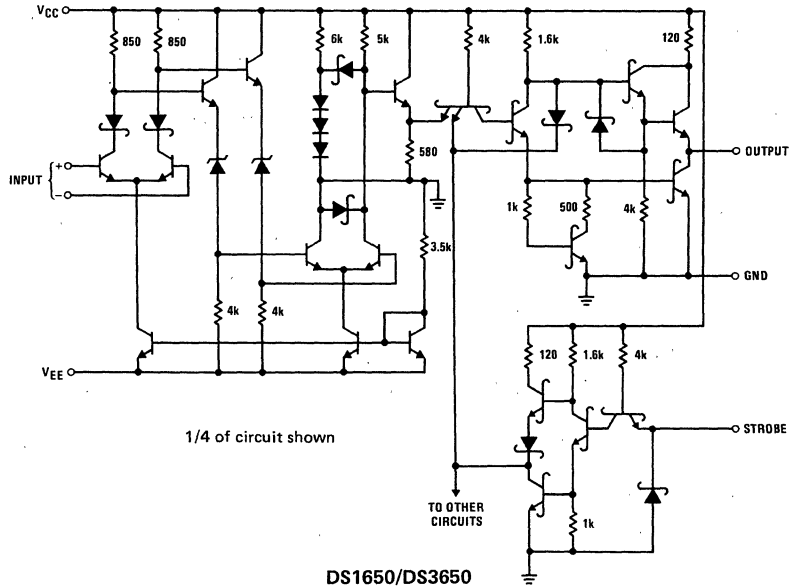


Note. E_{IN} waveform characteristics:
 t_{PLH} and $t_{PHL} \leq 10$ ns measured 10% to 90%
 PRR = 1 MHz
 Duty Cycle = 500 ns

Note. Output of Channel B shown under test, other channels are tested similarly.

FIGURE 10. Strobe Propagation Delay $t_{PLH}(S)$ and $t_{PHL}(S)$

Schematic Diagrams



DS1691A/DS3691 (RS-422/RS-423) Line Drivers with TRI-STATE®

General Description

The DS1691A/DS3691 are low power Schottky TTL line drivers designed to meet the requirements of EIA standards RS-422 and RS-423. They feature 4 buffered outputs with high source and sink current capability with internal short circuit protection. A mode control input provides a choice of operation either as 4 independent line drivers or 2 differential line drivers. A rise time control pin allows the use of an external capacitor to reduce rise time for suppression of near end crosstalk to other receivers in the cable.

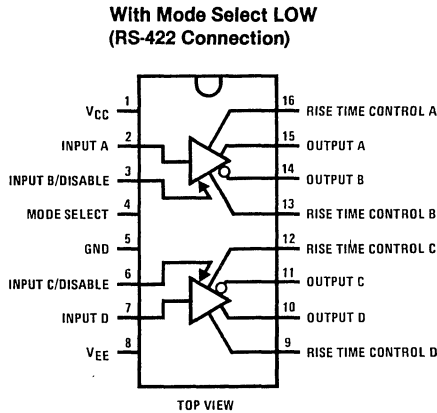
With the mode select pin low, the DS1691A/DS3691 are dual differential line drivers with TRI-STATE outputs. They feature $\pm 10V$ output common-mode range in TRI-STATE and 0V output unbalance when operated with $\pm 5V$ supply.

Features

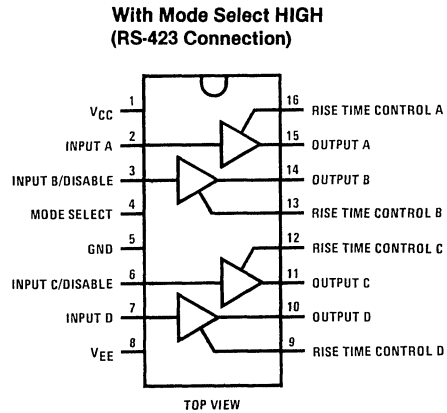
- Dual RS-422 line driver with mode pin low, or quad RS-423 line driver with mode pin high
- Individually TRI-STATEable differential drivers in differential mode
- Short circuit protection for both source and sink outputs
- Outputs will not clamp line with power off or in TRI-STATE
- Individual rise time control for each output
- 100 Ω transmission line drive capability
- Low I_{CC} and I_{EE} power consumption

RS-422	35 mW/driver typ
RS-423	26 mW/driver typ
- Low current PNP inputs compatible with TTL, MOS and CMOS

Connection Diagram



Connection Diagram



Truth Table

Operation	Inputs			Outputs	
	Mode	A (D)	B (C)	A (D)	B (C)
RS-422	0	0	0	0	1
	0	0	1	TRI-STATE	TRI-STATE
	0	1	0	1	0
	0	1	1	TRI-STATE	TRI-STATE
RS-423	1	0	0	0	0
	1	0	1	0	1
	1	1	0	1	0
	1	1	1	1	1

Order Number DS1691AJ, DS3691J or DS3691N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	
V_{CC}	7V
V_{EE}	-7V
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Input Voltage	15V
Output Voltage (Power OFF)	± 15V
Storage Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.9 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
Supply Voltage			
DS1691A			
V_{CC}	4.5	5.5	V
V_{EE}	-4.5	-5.5	V
DS3691			
V_{CC}	4.75	5.25	V
V_{EE}	-4.75	-5.25	V
Temperature (T_A)			
DS1691A	-55	+125	°C
DS3691	0	+70	°C

DC Electrical Characteristics (Notes 2, 3, 4 and 5)

Parameter	Conditions	Min	Typ	Max	Units	
RS-422 CONNECTION, V_{EE} CONNECTION TO GROUND, MODE SELECT ≤ 0.8V						
V_{IH}	High Level Input Voltage	2			V	
V_{IL}	Low Level Input Voltage			0.8	V	
I_{IH}	High Level Input Current	$V_{IN} = 2.4V$	1	40	μA	
		$V_{IN} \leq 15V$	10	100	μA	
I_{IL}	Low Level Input Current	$V_{IN} = 0.4V$	-30	-200	μA	
V_I	Input Clamp Voltage	$I_{IN} = -12 mA$		-1.5	V	
V_O $\overline{V_O}$	Differential Output Voltage $V_{A,B}$	$R_L = \infty$	$V_{IN} = 2V$	3.6	6.0	V
			$V_{IN} = 0.8V$	-3.6	-6.0	V
V_T $\overline{V_T}$	Differential Output Voltage $V_{A,B}$	$R_L = 100\Omega$ $V_{CC} \geq 4.75V$	$V_{IN} = 2V$	2	2.4	V
			$V_{IN} = 0.8V$	-2	-2.4	V
$V_{OS}, \overline{V_{OS}}$	Common-Mode Offset Voltage	$R_L = 100\Omega$		2.5	3	V
$ V_T - \overline{V_T} $	Difference in Differential Output Voltage	$R_L = 100\Omega$		0.05	0.4	V
$ V_{OS} - \overline{V_{OS}} $	Difference in Common-Mode Offset Voltage	$R_L = 100\Omega$		0.05	0.4	V
V_{SS}	$ V_T - \overline{V_T} $	$R_L = 100\Omega, V_{CC} \geq 4.75V$	4.0	4.8		V
V_{CMR}	Output Voltage Common-Mode Range	$V_{DISABLE} = 2.4V$	± 10			V
I_{XA} I_{XB}	Output Leakage Current Power OFF	$V_{CC} = 0V$	$V_{CMR} = 10V$		100	μA
			$V_{CMR} = -10V$		-100	μA
I_{OX}	TRI-STATE Output Current	$V_{CC} = Max$	$V_{CMR} \leq 10V$		100	μA
			$V_{CMR} \geq -10V$		-100	μA
I_{SA}	Output Short Circuit Current	$V_{IN} = 2.4V$	$V_{OA} = 6V$	80	150	mA
			$V_{OB} = 0V$	-80	-150	mA
I_{SB}	Output Short Circuit Current	$V_{IN} = 0.4V$	$V_{OA} = 0V$	-80	-150	mA
			$V_{OB} = 6V$	80	150	mA
I_{CC}	Supply Current			18	30	mA

AC Electrical Characteristics $T_A = 25^\circ\text{C}$ (Note 5)

Parameter		Conditions	Min	Typ	Max	Units
RS-422 CONNECTION, $V_{CC} = 5\text{V}$, MODE SELECT = 0.8V						
t_r	Output Rise Time	$R_L = 100\Omega$, $C_L = 500\text{ pF}$ (Figure 1)		120	200	ns
t_f	Output Fall Time	$R_L = 100\Omega$, $C_L = 500\text{ pF}$ (Figure 1)		120	200	ns
t_{PDH}	Output Propagation Delay	$R_L = 100\Omega$, $C_L = 500\text{ pF}$ (Figure 1)		120	200	ns
t_{PDL}	Output Propagation Delay	$R_L = 100\Omega$, $C_L = 500\text{ pF}$ (Figure 1)		120	200	ns
t_{PZL}	TRI-STATE Delay	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 0\text{ pF}$ (Figure 4)		250	350	ns
t_{PZH}	TRI-STATE Delay	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 0\text{ pF}$ (Figure 4)		180	300	ns
t_{PLZ}	TRI-STATE Delay	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 0\text{ pF}$ (Figure 4)		180	300	ns
t_{PHZ}	TRI-STATE Delay	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 0\text{ pF}$ (Figure 4)		250	350	ns

DC Electrical Characteristics (Notes 2, 3, 4 and 5)

Parameter		Conditions	Min	Typ	Max	Units	
RS-423 CONNECTION, $V_{CC} = V_{EE}$, MODE SELECT $\geq 2\text{V}$							
V_{IH}	High Level Input Voltage		2			V	
V_{IL}	Low Level Input Voltage				0.3	V	
I_{IH}	High Level Input Current	$V_{IN} = 2.4\text{V}$ $V_{IN} \leq 15\text{V}$		1 10	40 100	μA μA	
I_{IL}	Low Level Input Current	$V_{IN} = 0.4\text{V}$		-30	-200	μA	
V_I	Input Clamp Voltage	$I_{IN} = -12\text{ mA}$			-1.5	V	
V_O $\overline{V_O}$	Output Voltage	$R_L = \infty$, (Note 6) $V_{CC} \geq 4.75\text{V}$	$V_{IN} = 2\text{V}$ $V_{IN} = 0.4\text{V}$	4.0 -4.0	4.4 -4.4	6.0 -6.0	V V
V_T $\overline{V_T}$	Output Voltage	$R_L = 450\Omega$, $V_{CC} \geq 4.75\text{V}$	$V_{IN} = 2.4\text{V}$ $V_{IN} = 0.4\text{V}$	3.6 -3.6	4.1 -4.1	V V	
$ V_T - \overline{V_T} $	Output Unbalance	$ V_{CC} = V_{EE} = 4.75\text{V}$, $R_L = 450\Omega$		0.02	0.4	V	
I_{X^+}	Output Leakage Power OFF	$V_{CC} = V_{EE} = 0\text{V}$	$V_O = 6\text{V}$	2	100	μA	
I_{X^-}	Output Leakage Power OFF	$V_{CC} = V_{EE} = 0\text{V}$	$V_O = -6\text{V}$	-2	-100	μA	
I_{S^+}	Output Short Circuit Current	$V_O = 0\text{V}$	$V_{IN} = 2.4\text{V}$	-80	-150	mA	
I_{S^-}	Output Short Circuit Current	$V_O = 0\text{V}$	$V_{IN} = 0.4\text{V}$	80	150	mA	
I_{SLEW}	Slew Control Current			± 140		μA	
I_{CC}	Positive Supply Current	$V_{IN} = 0.4\text{V}$, $R_L = \infty$		18	30	mA	
I_{EE}	Negative Supply Current	$V_{IN} = 0.4\text{V}$, $R_L = \infty$		-10	-22	mA	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the -55°C to $+125^\circ\text{C}$ temperature range for the DS1691A and across the 0°C to $+70^\circ\text{C}$ range for the DS3691. All typicals are given for $V_{CC} = 5\text{V}$ and $T_A = 25^\circ\text{C}$. V_{CC} and V_{EE} as listed in operating conditions.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

Note 5: Symbols and definitions correspond to EIA RS-422 and/or RS-423 where applicable.

Note 6: At -55°C , the output voltage is $+3.9\text{V}$ minimum and -3.9V minimum.

AC Electrical Characteristics $T_A = 25^\circ\text{C}$ (Note 5)

Parameter	Conditions	Min	Typ	Max	Units
RS-423 CONNECTION, $V_{CC} = 5\text{V}$, $V_{EE} = -5\text{V}$, MODE SELECT = 2.4V					
t_r	Rise Time	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 0$ (Figure 2)	120	300	ns
t_f	Fall Time	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 0$ (Figure 2)	120	300	ns
t_r	Rise Time	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 50\text{ pF}$ (Figure 3)	3.0		μs
t_f	Fall Time	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 50\text{ pF}$ (Figure 3)	3.0		μs
t_{rc}	Rise Time Coefficient	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 50\text{ pF}$ (Figure 3)	0.06		$\mu\text{s/pF}$
t_{PDH}	Output Propagation Delay	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 0$ (Figure 2)	180	300	ns
t_{PDL}	Output Propagation Delay	$R_L = 450\Omega$, $C_L = 500\text{ pF}$, $C_C = 0$ (Figure 2)	180	300	ns

AC Test Circuits and Switching Time Waveforms

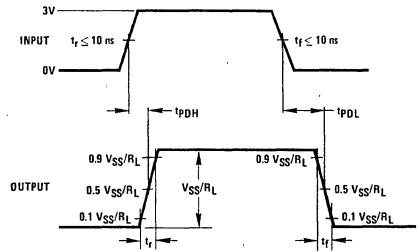
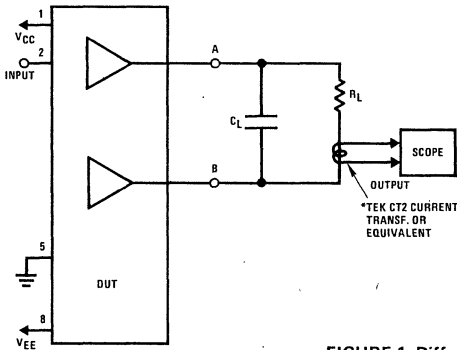


FIGURE 1. Differential Connection

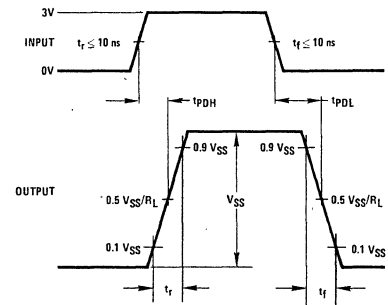
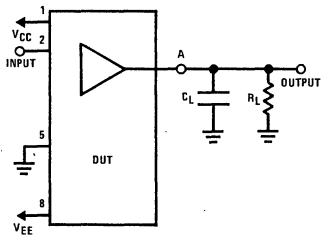


FIGURE 2. RS-423 Connection

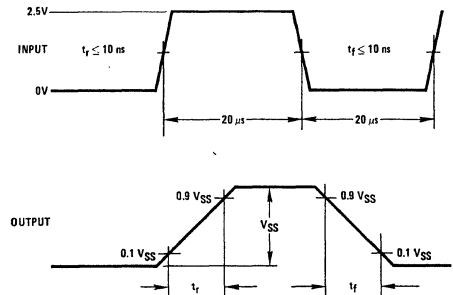
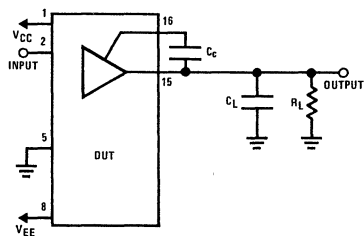


FIGURE 3. Rise Time Control for RS-423

AC Test Circuits and Switching Time Waveforms (Continued)

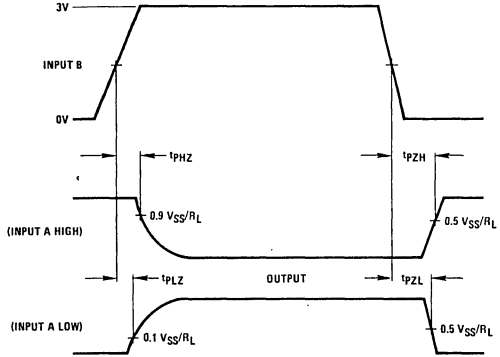
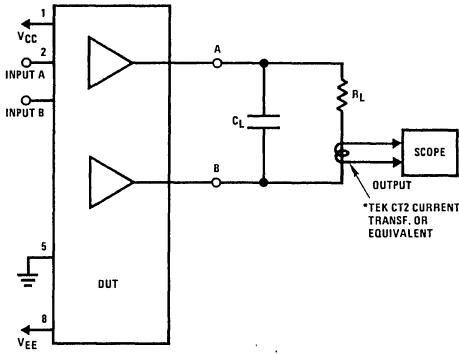
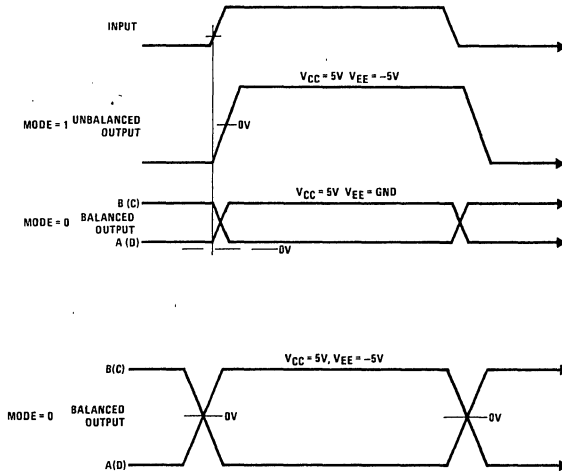


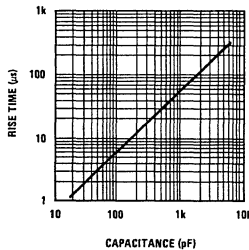
FIGURE 4. TRI-STATE® Delays

Switching Waveforms



Typical Rise Time Control Characteristics

Rise Time vs External Capacitor



DS1692/DS3692 TRI-STATE® Differential Line Drivers

General Description

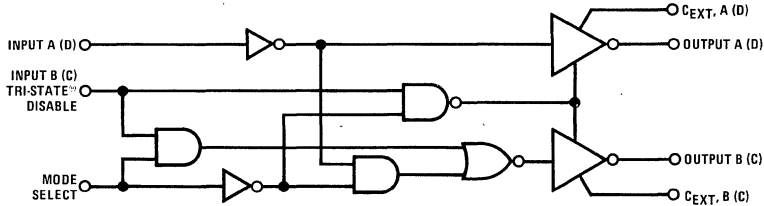
The DS1692/DS3692 are low power Schottky TTL line drivers electrically similar to the DS1691A/DS3691 but tested to meet the requirements of MIL-STD-188-114. They feature 4 buffered outputs with high source and sink current capability with internal short circuit protection. A mode control input provides a choice of operation either as 4 independent line drivers or 2 differential line drivers. A rise time control pin allows the use of an external capacitor to reduce rise time for suppression of near end crosstalk to other receivers in the cable.

With the mode select pin low, the DS1692/DS3692 are dual differential line drivers with TRI-STATE outputs. They feature $\pm 10V$ output common-mode range in TRI-STATE and 0V output unbalance when operated with $\pm 5V$ supply.

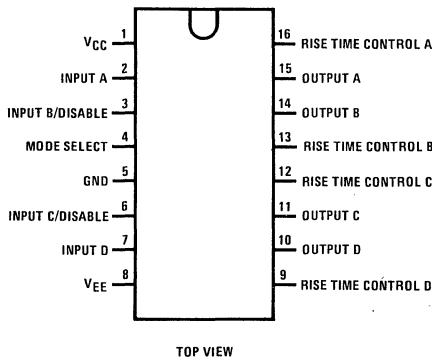
Features

- Dual differential line driver or quad single-ended line driver
- Individually TRI-STATEable differential drivers meet MIL-STD-188-114
- Short circuit protection for both source and sink outputs
- Individual rise time control for each output
- 100Ω transmission line drive capability
- Low I_{CC} and I_{EE} power consumption
 - Differential mode 35 mW/driver typ
 - Single-ended mode 26 mW/driver typ
- Low current PNP inputs compatible with TTL, MOS and CMOS

Logic Diagram (1/2 Circuit Shown)



Connection Diagram



Truth Table

Mode	Inputs		Outputs	
	A (D)	B (C)	A (D)	B (C)
0	0	0	0	1
0	0	1	TRI-STATE	TRI-STATE
0	1	0	1	0
0	1	1	TRI-STATE	TRI-STATE
1	0	0	0	0
1	0	1	0	1
1	1	0	1	0
1	1	1	1	1

Order Number DS1692J, DS3692J or DS3692N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	
V_{CC}	7V
V_{EE}	-7V
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Input Voltage	15V
Output Voltage (Power OFF)	± 15V
Storage Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.9 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
Supply Voltage			
DS1692			
V_{CC}	4.5	5.5	V
V_{EE}	-4.5	-5.5	V
DS3692			
V_{CC}	4.75	5.25	V
V_{EE}	-4.75	-5.25	V
Temperature (T_A)			
DS1692	-55	+125	°C
DS3692	0	+70	°C

Electrical Characteristics DS1692/DS3692 (Notes 2, 3 and 4)

Parameter	Conditions	Min	Typ	Max	Units		
DS1692, $V_{CC} = 5V \pm 10\%$, DS3692, $V_{CC} = 5V \pm 5\%$, V_{EE} CONNECTION TO GROUND, MODE SELECT $\leq 0.8V$							
$\frac{V_O}{V_O}$	Differential Output Voltage $V_{A,B}$	$R_L = \infty$	$V_{IN} = 2V$	2.5	3.6	V	
			$V_{IN} = 0.8V$	-2.5	-3.6	V	
$\frac{V_T}{V_T}$	Differential Output Voltage $V_{A,B}$	$R_L = 100\Omega$ $V_{CC} \geq 4.75V$	$V_{IN} = 2V$	2	2.6	V	
			$V_{IN} = 0.8V$	-2	-2.6	V	
$V_{OS}, \overline{V_{OS}}$	Common-Mode Offset Voltage	$R_L = 100\Omega$		2.5	3	V	
$ V_T - \overline{V_T} $	Difference in Differential Output Voltage	$R_L = 100\Omega$		0.05	0.4	V	
$ V_{OS} - \overline{V_{OS}} $	Difference in Common-Mode Offset Voltage	$R_L = 100\Omega$		0.05	0.4	V	
V_{SS}	$ V_T - \overline{V_T} $	$R_L = 100\Omega, V_{CC} \geq 4.75V$	4.0	4.8		V	
I_{OX}	TRI-STATE Output Current	$V_O \leq -10V$		-0.002	-0.15	mA	
		$V_O \geq 15V$		0.002	0.15	mA	
I_{SA}	Output Short Circuit Current	$V_{IN} = 2.4V$	$V_{OA} = 6V$		80	150	mA
			$V_{OB} = 0V$		-80	-150	mA
I_{SB}	Output Short Circuit Current	$V_{IN} = 0.4V$	$V_{OA} = 0V$		-80	-150	mA
			$V_{OB} = 6V$		80	150	mA
I_{CC}	Supply Current		18	30	mA		
DS1692, $V_{CC} = 5V \pm 10\%$, $V_{EE} = -5V \pm 10\%$, DS3692, $V_{CC} = 5V \pm 5\%$, $V_{EE} = -5 \pm 5\%$, MODE SELECT $\leq 0.8V$							
$\frac{V_O}{V_O}$	Differential Output Voltage $V_{A,B}$	$R_L = \infty$	$V_{IN} = 2.4V$	7	8.5	V	
			$V_{IN} = 0.4V$	-7	-8.5	V	
$\frac{V_T}{V_T}$	Differential Output Voltage $V_{A,B}$	$R_L = 200\Omega$	$V_{IN} = 2.4V$	6	7.3	V	
			$V_{IN} = 0.4V$	-6	-7.3	V	
$ V_T - \overline{V_T} $	Output Unbalance	$ V_{CC} = V_{EE} , R_L = 200\Omega$		0.02	0.4	V	
I_{OX}	TRI-STATE Output Current		$V_O = 10V$		0.002	0.15	mA
			$V_O = -10V$		-0.002	-0.15	mA
I_{S^+} I_{S^-}	Output Short Circuit Current	$V_O = 0V$	$V_{IN} = 2.4V$		-80	-150	mA
			$V_{IN} = 0.4V$		80	150	mA
I_{SLEW}	Slew Control Current			± 140		μA	
I_{CC}	Positive Supply Current	$V_{IN} = 0.4V, R_L = \infty$		18	30	mA	
I_{EE}	Negative Supply Current	$V_{IN} = 0.4V, R_L = \infty$		-10	-22	mA	

Electrical Characteristics (Notes 2 and 3) $V_{EE} \leq 0V$

Parameter	Conditions	Min	Typ	Max	Units	
V_{IH} High Level Input Voltage		2			V	
V_{IL} Low Level Input Voltage				0.8	V	
I_{IH} High Level Input Current	$V_{IN} = 2.4V$		1	40	μA	
	$V_{IN} \leq 15V$		10	100	μA	
I_{IL} Low Level Input Current	$V_{IN} = 0.4V$		-30	-200	μA	
V_I Input Clamp Voltage	$I_{IN} = -12 mA$			-1.5	V	
I_{XA} Output Leakage Current	$V_{CC} = V_{EE} = 0$	$V_O = 15V$		0.01	0.15	mA
I_{XB} Power OFF		$V_O = -15V$		-0.01	-0.15	mA

Switching Characteristics $T_A = 25^\circ C$

Parameter	Conditions	Min	Typ	Max	Units
$V_{CC} = 5V, MODE\ SELECT = 0.8V$					
t_r Differential Output Rise Time	$R_L = 100\Omega, C_L = 500\text{ pF}$ (Figure 1)		120	200	ns
t_f Differential Output Fall Time	$R_L = 100\Omega, C_L = 500\text{ pF}$ (Figure 1)		120	200	ns
t_{PDH} Output Propagation Delay	$R_L = 100\Omega, C_L = 500\text{ pF}$ (Figure 1)		120	200	ns
t_{PDL} Output Propagation Delay	$R_L = 100\Omega, C_L = 500\text{ pF}$ (Figure 1)		120	200	ns
t_{PZL} TRI-STATE Delay	$R_L = 100\Omega, C_L = 500\text{ pF}$ (Figure 2)		180	250	ns
t_{PZH} TRI-STATE Delay	$R_L = 100\Omega, C_L = 500\text{ pF}$ (Figure 2)		180	250	ns
t_{PLZ} TRI-STATE Delay	$R_L = 100\Omega, C_L = 500\text{ pF}$ (Figure 2)		80	150	ns
t_{PHZ} TRI-STATE Delay	$R_L = 100\Omega, C_L = 500\text{ pF}$ (Figure 2)		80	150	ns
$V_{CC} = 5V, V_{EE} = -5V, MODE\ SELECT = 0.8V$					
t_r Differential Output Rise Time	$R_L = 200\Omega, C_L = 500\text{ pF}$ (Figure 1)		190	300	ns
t_f Differential Output Fall Time	$R_L = 200\Omega, C_L = 500\text{ pF}$ (Figure 1)		190	300	ns
t_{PDL} Output Propagation Delay	$R_L = 200\Omega, C_L = 500\text{ pF}$ (Figure 1)		190	300	ns
t_{PDH} Output Propagation Delay	$R_L = 200\Omega, C_L = 500\text{ pF}$ (Figure 1)		190	300	ns
t_{PZL} TRI-STATE Delay	$R_L = 200\Omega, C_L = 500\text{ pF}$ (Figure 2)		180	250	ns
t_{PZH} TRI-STATE Delay	$R_L = 200\Omega, C_L = 500\text{ pF}$ (Figure 2)		180	250	ns
t_{PLZ} TRI-STATE Delay	$R_L = 200\Omega, C_L = 500\text{ pF}$ (Figure 2)		80	150	ns
t_{PHZ} TRI-STATE Delay	$R_L = 200\Omega, C_L = 500\text{ pF}$ (Figure 2)		80	150	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the $-55^\circ C$ to $+125^\circ C$ temperature range for the DS1692 and across the $0^\circ C$ to $+70^\circ C$ range for the DS3692. All typicals are given for $V_{CC} = 5V$ and $T_A = 25^\circ C$. V_{CC} and V_{EE} as listed in operating conditions.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

AC Test Circuits and Switching Time Waveforms

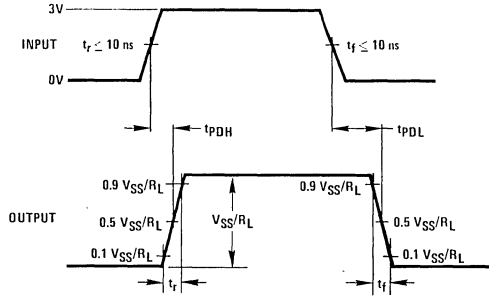
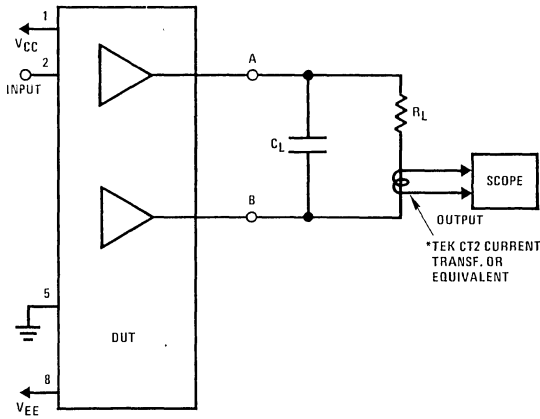


FIGURE 1. Differential Connection

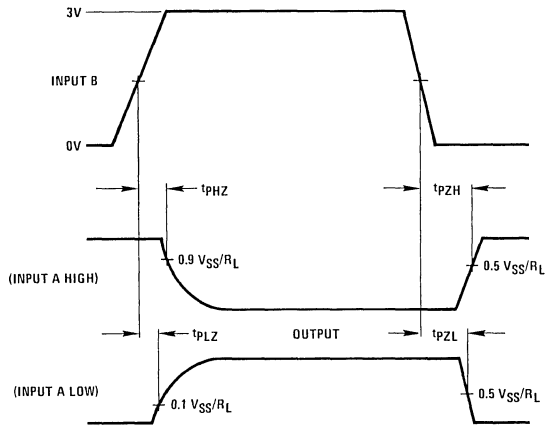
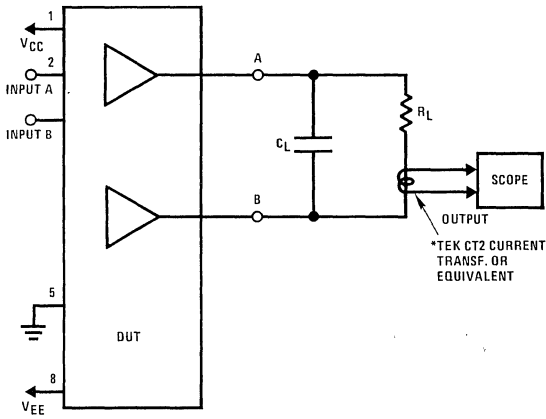
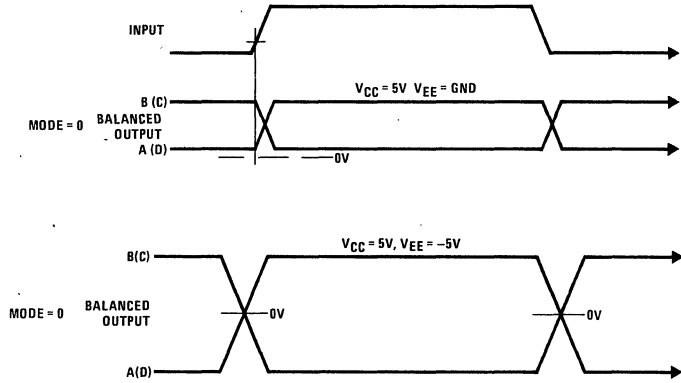
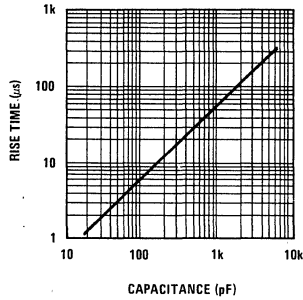


FIGURE 2. TRI-STATE Delays for DS1692/DS3692

Switching Waveforms



Typical Rise Time Control Characteristics



DS3695/DS3696/DS3697/DS3698 Differential TRI-STATE® Bus/Line Transceivers/Repeaters

General Description

The DS3695, DS3696, DS3697 and DS3698 are high speed differential TRI-STATE bus/line transceivers/repeaters designed to meet the requirements of EIA standard RS485 with extended common mode range (+12V to -7V), for multipoint data transmission.

The driver and receiver outputs feature TRI-STATE capability, for the driver outputs over the entire common mode range of +12V to -7V. Bus contention or fault situations that cause excessive power dissipation within the device are handled by a thermal shutdown circuit, which forces the driver outputs into the high impedance state. The DS3696 and DS3698 provide an output pin which reports the occurrence of a line fault causing thermal shutdown of the device. This is an "open collector" pin with an internal 10 kΩ pull-up resistor. This allows the line fault outputs of several devices to be wire OR-ed.

Both AC and DC specifications are guaranteed over the 0 to 70°C temperature and 4.75V to 5.25V supply voltage range.

TRI-STATE® is a registered trademark of National Semiconductor Corp.

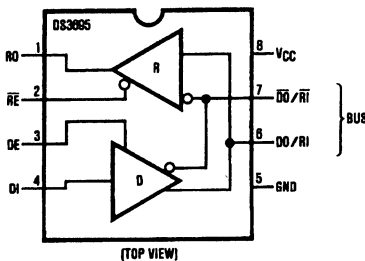
Features

- Meets new EIA standard RS485 (PN1488), for multipoint bus transmission.
- 15 ns driver propagation delays with 2 ns skew (typical).
- Single channel per package isolates faulty channels (from shutting down good channels).
- Single +5V supply.
- -7V to +12V bus common mode range permits ±7V ground difference between devices on the bus.
- Thermal shutdown protection.
- Power-up down glitch-free driver outputs permit live insertion or removal of transceivers.
- High impedance to bus with driver in TRI-STATE or with power off, over the entire common mode range allows the unused devices on the bus to be powered down.
- Line fault reporting capability on DS3696 and DS3698 allows automated fault location and re-routing under processor control.
- 12 kΩ Minimum receiver input impedance.
- 70 mV typical receiver hysteresis.

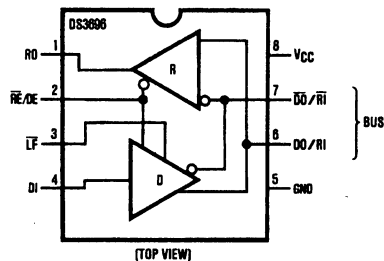
DS3695/96/97/98

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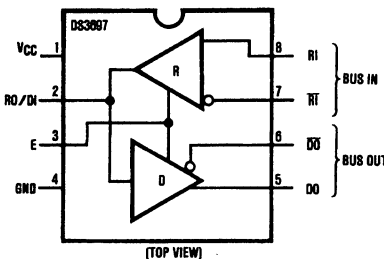
Connection and Logic Diagrams



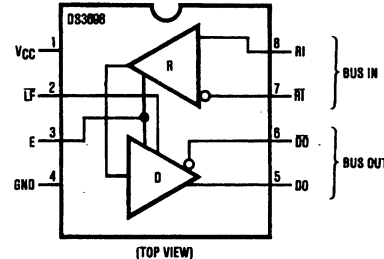
TL/F/5272-1



TL/F/5272-2



TL/F/5272-3



TL/F/5272-4

Order Number DS3695N, DS3696N,
DS3697N or DS3698N
See NS Package N08E

Absolute Maximum Ratings (Note 1)

Supply voltage, V_{CC}	7V
Control input voltages	7V
Driver input voltage	7V
Driver output voltages	+15V / -10V
Receiver input voltages (DS3695, DS3696)	+15V / -10V
Receiver common mode voltage (DS3697, DS3698)	±25V
Receiver output voltage	5.5V
Continuous power dissipation @70°C	780 mW
Storage temperature range	-65°C to +150°C
Lead temperature (Soldering 10 seconds)	300°C

Recommended Operating Conditions

	Min	Max	Units
Supply voltage, V_{CC}	4.75	5.25	V
Bus voltage	-7	+12	V
Operating free air temperature T_A	0	70	°C

Electrical Characteristics (Notes 2 and 3) - (0°C ≤ T_A ≤ 70°C, 4.75V < V_{CC} < 5.25V unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{OD1}	Differential Driver Output Voltage (Unloaded)	$I_O = 0$			5	V
V_{OD2}	Differential Driver Output Voltage (with Load)	(Figure 1)	1.5			V
ΔV_{OD}	Change in Magnitude of Driver Differential Output Voltage For Complementary Output States	(Figure 1)			0.2	V
V_{OC}	Driver Common Mode Output Voltage	(Figure 1)			3.0	V
$\Delta V_{OC} $	Change in Magnitude of Driver Common Mode Output Voltage For Complementary Output States	(Figure 1)			0.2	V
V_{IH}	Input High Voltage	DI, DE, RE, E	2			V
V_{IL}	Input Low Voltage				0.8	V
V_{CL}	Input Clamp Voltage		$I_{IN} = -18 \text{ mA}$		-1.5	V
I_{IL}	Input Low Current		$V_{IL} = 0.4 \text{ V}$		-360	μA
I_{IH}	Input High Current		$V_{IH} = 2.4 \text{ V}$		20	μA
I_{OZD}	TRI-STATE OUTPUT Current for Driver	$V_{CC} = 0 \text{ V}$ or $V_{CC} = \text{Max}$			+1	mA
		$V_O = -7 \text{ V}$			-0.8	mA
V_{TH}	Differential Input Threshold Voltage for Receiver	$V_{OUT} = V_{OL}$ or V_{OH} $-7 \text{ V} \leq V_{CM} \leq +12 \text{ V}$	-0.2		+0.2	V
ΔV_{TH}	Receiver Input Hysteresis	$V_{CM} = 0 \text{ V}$		70		mV
V_{OH}	Receiver Output High Voltage	$I_{OH} = -400 \text{ } \mu\text{A}$	2.4			V
V_{OL}	Output Low Voltage	RO			0.5	V
		LF			0.45	
I_{OZR}	OFF-State (High Impedance) Output Current at Receiver	$V_{CC} = \text{Max}$ $0.4 \text{ V} \leq V_O \leq 2.4 \text{ V}$			±20	μA
R_{IN}	Receiver Input Resistance	$-7 \text{ V} \leq V_{CM} \leq +12 \text{ V}$	12			kΩ
I_{CC}	Supply current (total package)	No Load	Driver outputs enabled	40		mA
			Driver outputs disabled	23		mA
I_{OSD}	Driver Short-circuit Output current	Output voltage = -7V			-250	mA
		Output voltage = +12V			-250	mA
I_{OSR}	Receiver short-circuit Output current	$V_O = 0 \text{ V}$,	-15		-85	mA

Note 1. "Absolute maximum ratings" are those beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2. All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to device ground unless otherwise specified.

Note 3. All typicals are given for $V_{CC} = 5 \text{ V}$ and $T_A = 25^\circ \text{C}$.

Switching Characteristics (4.75V ≤ V_{CC} ≤ 5.25V; 0°C < T_A < 70°C)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t _{PLH}	Driver Input to Output	R _{LDIFF} = 60Ω		15		ns
t _{PHL}	Driver Input to Output	C _{L1} = C _{L2} = 100 pF		15		ns
Skew	Driver Output to Output	(Figures 3 and 5)		2		ns
t _{ZH}	Driver Enable to Output High	C _L = 100 pF (Figures 4 and 6) S1 open		33		ns
t _{ZL}	Driver Enable to Output Low	C _L = 100 pF (Figures 4 and 6) S2 open		33		ns
t _{LZ}	Driver Disable Time from Low	C _L = 15 pF (Figures 4 and 6) S2 Open		33		ns
t _{HZ}	Driver Disable Time from High	C _L = 15 pF (Figures 4 and 6) S1 Open		33		ns
t _{PLH}	Receiver Input to Output	C _L = 15 pF (Figures 2 and 7)		22		ns
t _{PHL}	Receiver Input to Output	S1 and S2 Closed		22		ns
t _{ZL}	Receiver Enable to Output Low	C _L = 15 pF (Figures 2 and 8) S2 Open		15		ns
t _{ZH}	Receiver Enable to Output High	C _L = 15 pF (Figures 2 and 8) S1 Open		15		ns
t _{LZ}	Receiver Disable from Low	C _L = 15 pF (Figures 2 and 8) S2 Open		12		ns
t _{HZ}	Receiver Disable from High	C _L = 15 pF (Figures 2 and 8) S1 Open		12		ns

AC Test Circuits

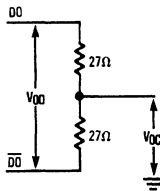
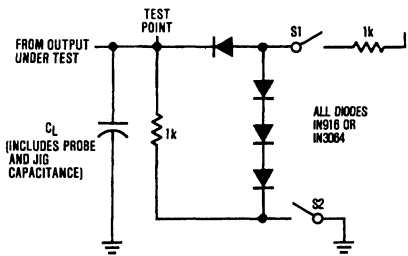


FIGURE 1.

TL/F/5272-5



TL/F/5272-6

Note: S1 and S2 of load circuit are closed except as otherwise mentioned.

FIGURE 2.

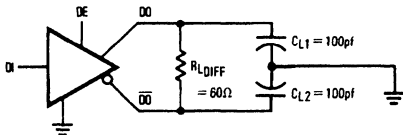
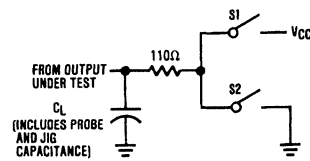


FIGURE 3.

TL/F/5272-7



TL/F/5272-8

Note: Unless otherwise specified the switches are closed.

FIGURE 4.

Switching Time Waveforms

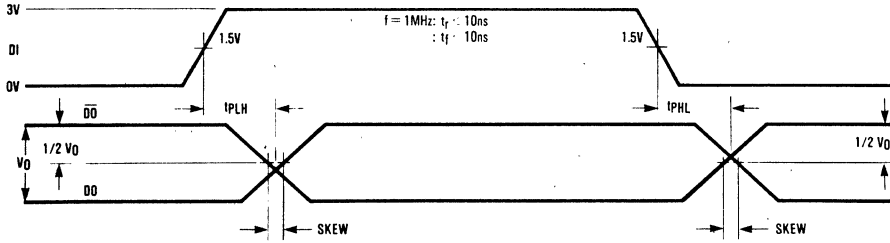


FIGURE 5. Driver Propagation Delays

TL/F/5272-9

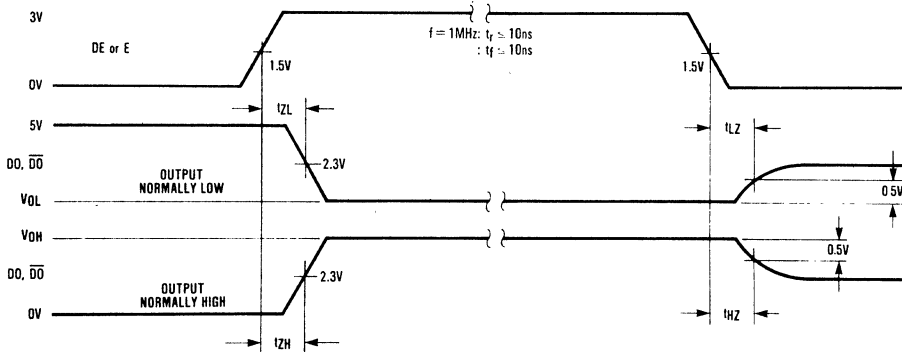
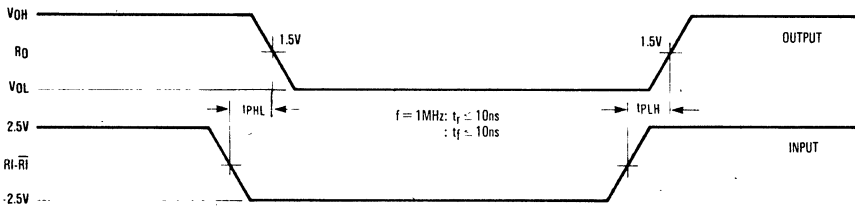


FIGURE 6. Driver Enable and Disable Times

TL/F/5272-10



Note: Differential input voltage may be realized by grounding \overline{RI} and pulsing RI between +2.5V and -2.5V

FIGURE 7. Receiver Propagation Delays

TL/F/5272-11

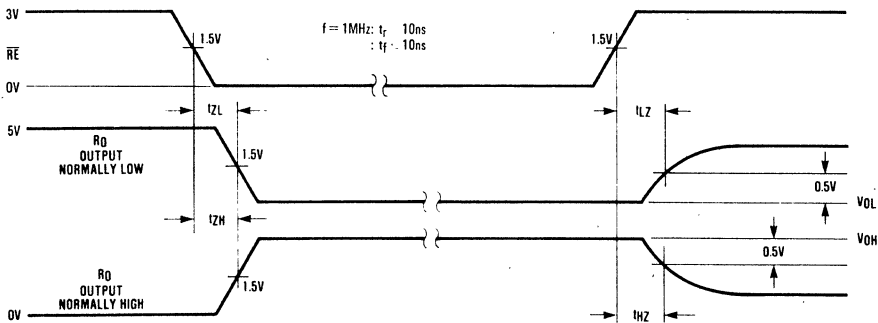


FIGURE 8. Receiver Enable and Disable Times

TL/F/5272-12

Function Tables

DS3695/DS3696 Transmitting

Inputs			Line Condition	Outputs		
\overline{RE}	DE	DI		\overline{DO}	DO	\overline{LF}^* (DS3696 Only)
X	1	1	No Fault	0	1	H
X	1	0	No Fault	1	0	H
X	0	X	X	Z	Z	H
X	1	X	Fault	Z	Z	L

DS3695/DS3696 Receiving

Inputs			Outputs	
\overline{RE}	DE	RI- \overline{RI}	RO	\overline{LF}^* (DS3696 Only)
0	0	$\geq +0.2V$	1	H
0	0	$\leq -0.2V$	0	H
0	0	Inputs Open	1	H
1	0	X	Z	H

DS3697/DS3698

Inputs		Line Condition	Outputs			
E	RI- \overline{RI}		\overline{DO}	DO	RO/DI (DS3697 Only)	\overline{LF}^* (DS3698 Only)
1	$\geq +0.2V$	No Fault	0	1	1	H
1	$\leq -0.2V$	No Fault	1	0	0	H
0	X	X	Z	Z	Z	H
1	$\geq +0.2V$	Fault	Z	Z	1	L
1	$\leq -0.2V$	Fault	Z	Z	0	L

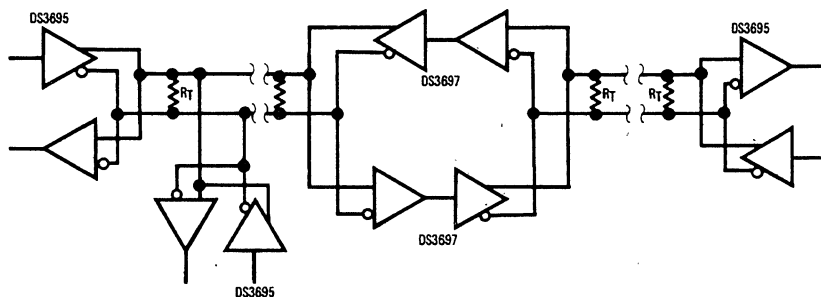
X — Don't care condition

Z — High impedance state

Fault — Improper line conditions causing excessive power dissipation in the driver, such as shorts or bus contention situations

* \overline{LF} is an "open collector" output with an on-chip 10 k Ω pull-up resistor

Typical Application



TL/F/5272-13

DS55113/DS75113 Dual TRI-STATE® Differential Line Driver

General Description

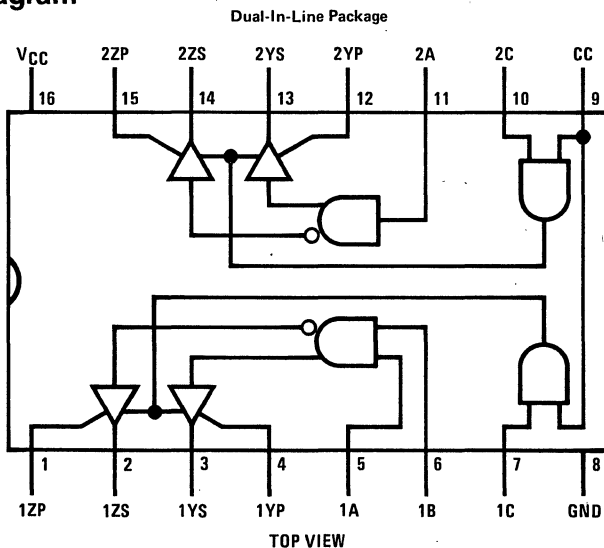
The DS55113/DS75113 dual differential line drivers with TRI-STATE outputs are designed to provide all the features of the DS55114/DS75114 line drivers with the added feature of driver output controls. There are individual controls for each output pair, as well as a common control for both output pairs. When an output control is low, the associated output is in a high-impedance state and the output can neither drive nor load the bus. This permits many devices to be connected together on the same transmission line for party-line applications.

The output stages are similar to TTL totem-pole outputs, but with the sink outputs, YS and ZS, and the corresponding active pull-up terminals, YP and ZP, available on adjacent package pins.

Features

- Each circuit offers choice of open-collector or active pull-up (totem-pole) outputs
- Single 5V supply
- Differential line operation
- Dual channels
- TTL/LS compatibility
- High-impedance output state for party-line applications
- Short-circuit protection
- High current outputs
- Single-ended or differential AND/NAND outputs
- Common and individual output controls
- Clamp diodes at inputs
- Easily adaptable to DS55114/DS75114 applications

Connection Diagram



Positive logic: Y = AB
Z = AB
Output is OFF when C or CC is low

Order Number DS55113J, DS75113J, or DS75113N
See NS Package J16A or N16A

Truth Table

INPUTS				OUTPUTS	
OUTPUT CONTROL		DATA		AND	NAND
C	CC	A	B*	Y	Z
L	X	X	X	Z	Z
X	L	X	X	Z	Z
H	H	L	X	L	H
H	H	X	L	L	H
H	H	H	H	H	L

H = high level
L = low level
X = irrelevant
Z = high impedance (OFF)
*B input and 4th line of truth table applicable only to driver number 1

Absolute Maximum Ratings (Note 1)

Supply Voltage (V_{CC}) (Note 1)	7V
Input Voltage	5.5V
OFF-State Voltage Applied to Open-Collector Outputs	12V
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Operating Free-Air Temperature Range	
DS55113	-55°C to +125°C
DS75113	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (1/16" from case for 60 seconds): J Package	300°C
Lead Temperature (1/16" from case for 10 seconds): N Package	260°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C (Note 2).

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})			
DS55113	4.5	5.5	V
DS75113	4.75	5.25	V
High Level Output Current (I_{OH})	-40		mA
Low Level Output Current (I_{OL})		40	mA
Operating Free-Air Temperature (T_A)			
DS55113	-55	125	°C
DS75113	0	70	°C

Electrical Characteristics Over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	CONDITIONS (Note 3)	DS55113			DS75113			UNITS		
		MIN	TYP (Note 4)	MAX	MIN	TYP (Note 4)	MAX			
V_{IH}	High Level Input Voltage	2			2			V		
V_{IL}	Low Level Input Voltage			0.8			0.8	V		
V_{IK}	Input Clamp Voltage	$V_{CC} = \text{Min}, I_I = -12 \text{ mA}$		-0.9	-1.5		-0.9	-1.5	V	
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}, V_{IH} = 2V, V_{IL} = 0.8V$	$I_{OH} = -10 \text{ mA}$	2.4	3.4		2.4	3.4	V	
			$I_{OH} = -40 \text{ mA}$	2	3.0		2	3.0		
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}, V_{IH} = 2V, V_{IL} = 0.8V, I_{OL} = 40 \text{ mA}$		0.23	0.4		0.23	0.4	V	
V_{OK}	Output Clamp Voltage	$V_{CC} = \text{Max}, I_O = -40 \text{ mA}$		-1.1	-1.5		-1.1	-1.5	V	
$I_{O(\text{off})}$	OFF-State Open-Collector Output Current	$V_{CC} = \text{Max}$	$V_{OH} = 12V$	$T_A = 25^\circ\text{C}$	1	10			μA	
				$T_A = 125^\circ\text{C}$		200				
			$V_{OH} = 5.25V$	$T_A = 25^\circ\text{C}$				1		10
				$T_A = 70^\circ\text{C}$						20
I_{OZ}	OFF-State (High-Impedance-State) Output Current	$V_{CC} = \text{Max},$ Output Controls at 0.8V	$T_A = \text{Max}$	$T_A = 25^\circ\text{C}, V_O = 0 \text{ to } V_{CC}$		± 10		± 10	μA	
				$V_O = 0$		-150		-20		
				$V_O = 0.4V$		± 80		± 20		
				$V_O = 2.4V$		± 80		± 20		
				$V_O = V_{CC}$		80		20		
I_I	Input Current at Maximum Input Voltage	A, B, C CC	$V_{CC} = \text{Max}, V_I = 5.5V$		1		1	mA		
					2		2			
I_{IH}	High Level Input Current	A, B, C CC	$V_{CC} = \text{Max}, V_I = 2.4V$		40		40	μA		
					80		80			
I_{IL}	Low Level Input Current	A, B, C CC	$V_{CC} = \text{Max}, V_I = 0.4V$		-1.6		-1.6	mA		
					-3.2		-3.2			
I_{OS}	Short-Circuit Output Current (Note 5)	$V_{CC} = \text{Max}, V_O = 0$		-40	-90	-120	-40	-90	-120	mA
I_{CC}	Supply Current (Both Drivers)	All Inputs at 0V, No Load, $T_A = 25^\circ\text{C}$	$V_{CC} = \text{Max}$	47	65		47	65	mA	
			$V_{CC} = 7V$	65	85		65	85		

Note 1: All voltage values are with respect to network ground terminal.

Note 2: For operation above 25°C free-air temperature, refer to Dissipation Derating Curves in the Thermal information section.

Note 3: All parameters with the exception of OFF-state open-collector output current are measured with the active pull-up connected to the sink output.

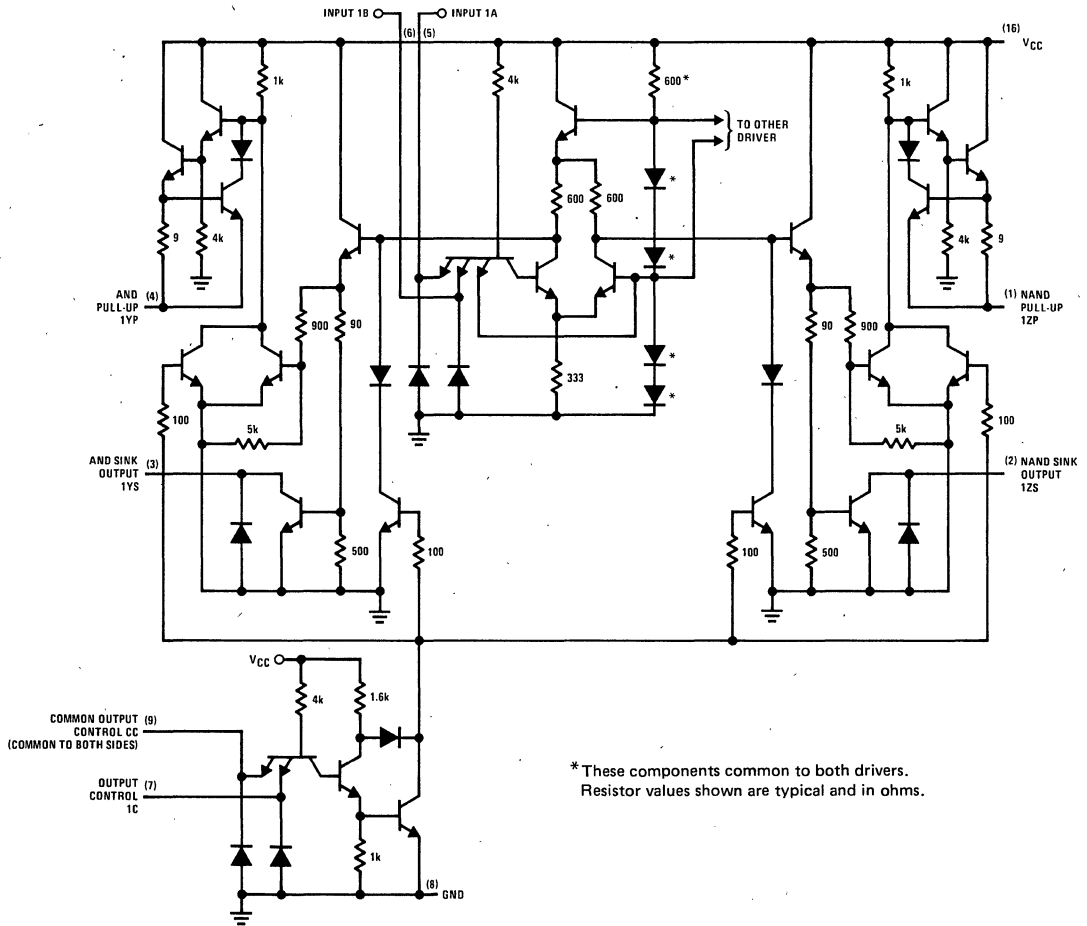
Note 4: All typical values are at $T_A = 25^\circ\text{C}$ and $V_{CC} = 5V$, with the exception of I_{CC} at 7V.

Note 5: Only one output should be shorted at a time, and duration of the short-circuit should not exceed one second.

Switching Characteristics $V_{CC} = 5V, C_L = 30\text{ pF}, T_A = 25^\circ\text{C}$

PARAMETER	CONDITIONS	DS55113			DS75113			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH} Propagation Delay Time, Low-to-High-Level Output	(Figure 1)		13	20		13	30	ns
t_{PHL} Propagation Delay Time, High-to-Low-Level Output			12	20		12	30	ns
t_{PZH} Output Enable Time to High Level	$R_L = 180\Omega$, (Figure 2)		7	15		7	20	ns
t_{PZL} Output Enable Time to Low Level	$R_L = 250\Omega$, (Figure 3)		14	30		14	40	ns
t_{PHZ} Output Disable Time from High Level	$R_L = 180\Omega$, (Figure 2)		10	20		10	30	ns
t_{PLZ} Output Disable Time from Low Level	$R_L = 250\Omega$, (Figure 3)		17	35		17	35	ns

Schematic Diagram (One side shown only)



* These components common to both drivers.
Resistor values shown are typical and in ohms.

AC Test Circuits and Switching Time Waveforms

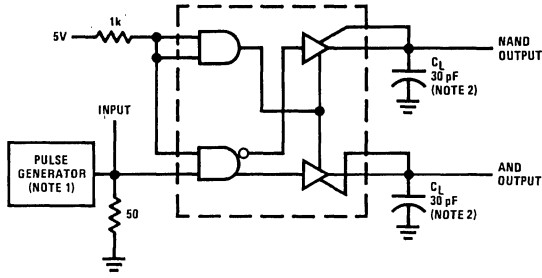


FIGURE 1. t_{pLH} and t_{pHL}

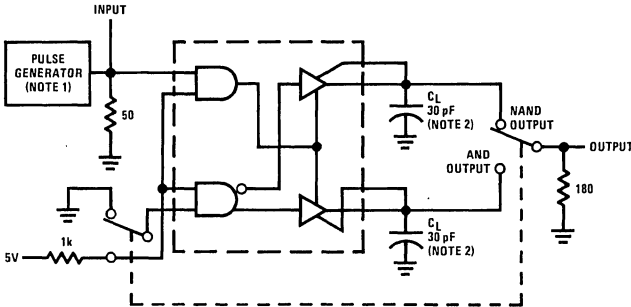
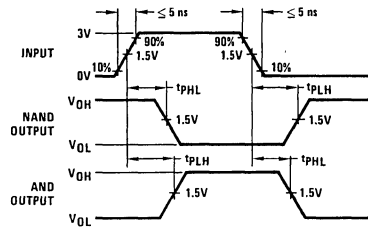


FIGURE 2. t_{pZH} and t_{pHZ}

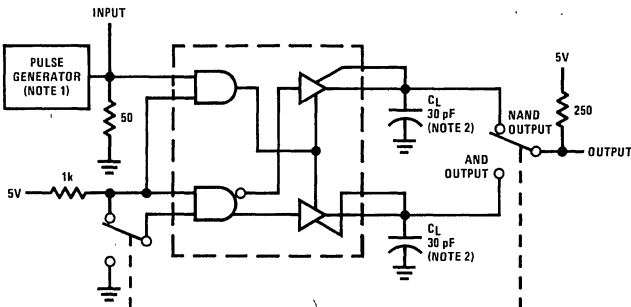
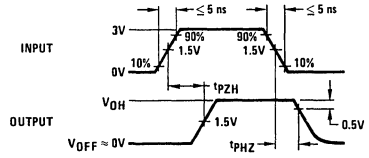
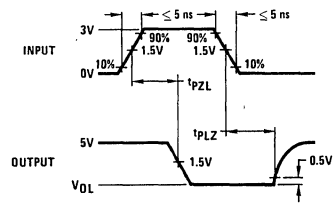
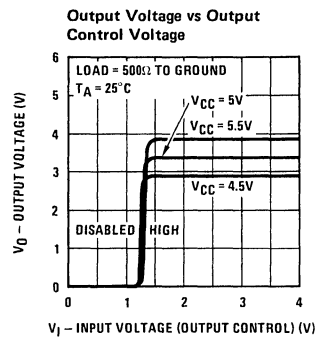
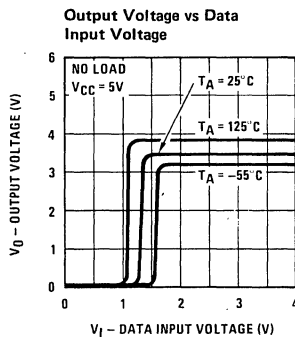
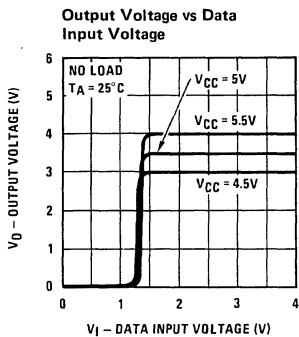


FIGURE 3. t_{pZL} and t_{pLZ}



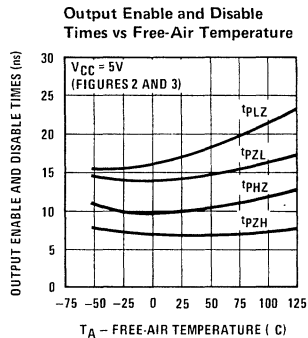
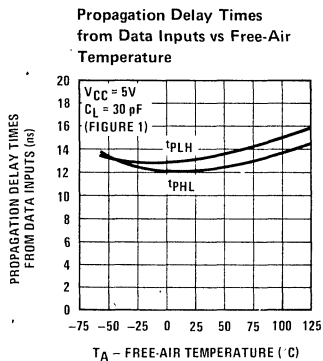
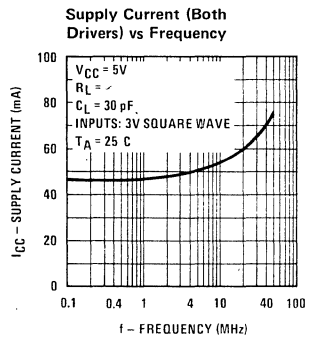
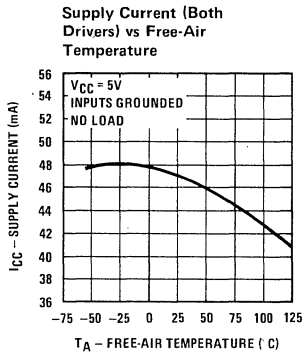
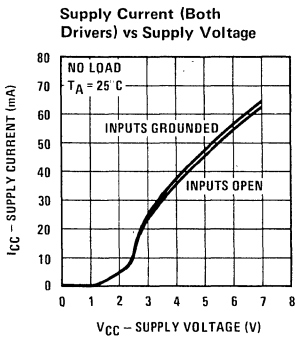
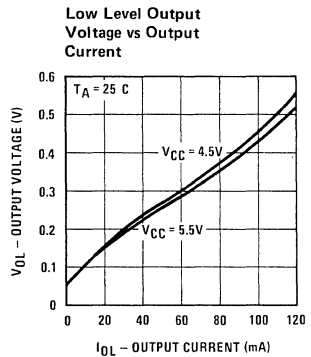
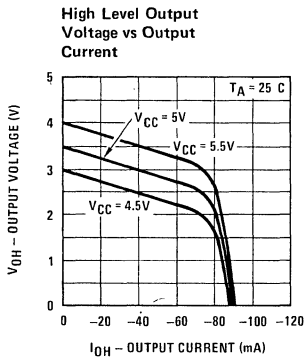
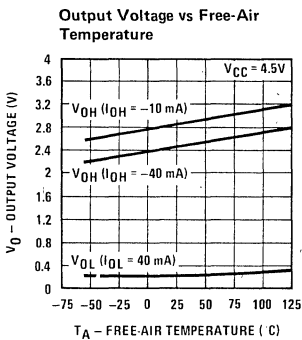
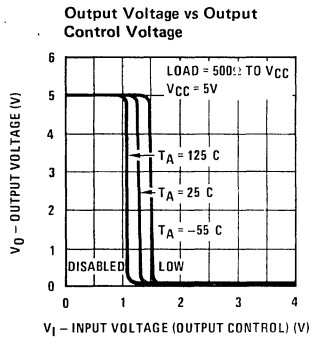
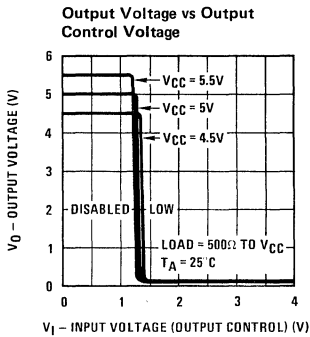
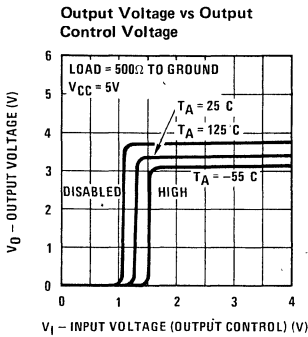
Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\Omega$, $PRR = 500\text{ kHz}$, $t_w = 100\text{ ns}$.
 Note 2: C_L includes probe and jig capacitance.

Typical Performance Characteristics*



*Data for temperatures below 0°C and above 70°C and for supply voltages below 4.75V and above 5.25V are applicable to DS55113 circuits only. These parameters were measured with the active pull-up connected to the sink output.

Typical Performance Characteristics* (Continued)



*Data for temperatures below 0°C and above 70°C and for supply voltages below 4.75V and above 5.25V are applicable to DS55113 circuits only. These parameters were measured with the active pull-up connected to the sink output.

DS55114/DS75114 Dual Differential Line Drivers

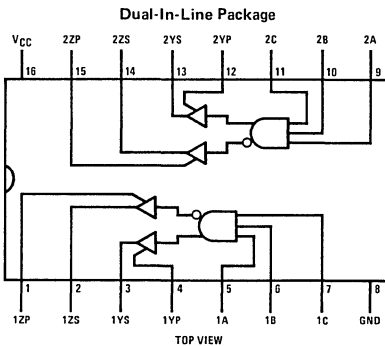
General Description

The DS55114/DS75114 dual differential line drivers are designed to provide differential output signals with high current capability for driving balanced lines, such as twisted pair at normal line impedances, without high power dissipation. The output stages are similar to TTL totem-pole outputs, but with the sink outputs, YS and ZS, and the corresponding active pull-up terminals, YP and ZP, available on adjacent package pins. Since the output stages provide TTL compatible output levels, these devices may also be used as TTL expanders or phase splitters.

Features

- Each circuit offers choice of open-collector or active pull-up (totem-pole) outputs
- Single 5V supply
- Differential line operation
- Dual channels
- TTL/LS compatibility
- Design to be interchangeable with Fairchild 9614 line drivers
- Short-circuit protection of outputs
- High current outputs
- Clamp diodes at inputs and outputs to terminate line transients
- Single-ended or differential AND/NAND outputs
- Triple inputs

Connection Diagram



Positive logic: $Y = ABC$
 $Z = ABC$

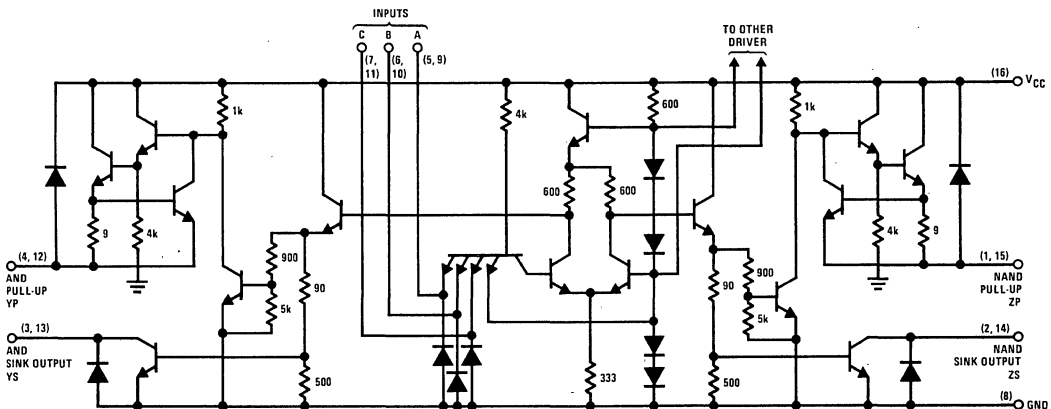
Order Number DS55114J, DS75114J, or DS75114N
See NS Package J16A or N16A

Truth Table

INPUTS			OUTPUTS	
A	B	C	Y	Z
H	H	H	H	L
All Other Input Combinations			L	H

H = high level
L = low level

Schematic Diagram (Each Driver)



Resistor values shown are typical and in ohms.

Absolute Maximum Ratings (Note 1)

Supply Voltage (V _{CC})	7V
Input Voltage	5.5V
OFF-State Voltage Applied to Open-Collector Outputs	12V
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Operating Free-Air Temperature Range	
DS55114	-55°C to +125°C
DS75114	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (1/16" from case for 60 seconds): J Package	300°C
Lead Temperature (1/16" from case for 10 seconds): N Package	260°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C (Note 2).

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS55114	4.5	5.5	V
DS75114	4.75	5.25	V
High Level Output Current (I _{OH})		-40	mA
Low Level Output Current (I _{OL})		40	mA
Operating Free-Air Temperature (T _A)			
DS55114	-55	125	°C
DS75114	0	70	°C

Electrical Characteristics Over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	CONDITIONS (Note 3)	DS55114			DS75114			UNITS	
		MIN	TYP (Note 4)	MAX	MIN	TYP (Note 4)	MAX		
V _{IH} High Level Input Voltage		2			2			V	
V _{IL} Low Level Input Voltage				0.8			0.8		
V _{IK} Input Clamp Voltage	V _{CC} = Min, I _I = -12 mA		-0.9	-1.5		-0.9	-1.5	V	
V _{OH} High Level Output Voltage	V _{CC} = Min, V _{IH} = 2V, I _{OH} = -10 mA	2.4	3.4		2.4	3.4		V	
	V _{IL} = 0.8V, I _{OH} = -40 mA	2	3.0		2	3.0			
V _{OL} Low Level Output Voltage	V _{CC} = Min, V _{IH} = 2V, V _{IL} = 0.8V, I _{OL} = 40 mA		0.2	0.4		0.2	0.45	V	
V _{OK} Output Clamp Voltage	V _{CC} = 5V, I _O = 40 mA, T _A = 25°C		6.1	6.5		6.1	6.5	V	
	V _{CC} = Max, I _O = -40 mA, T _A = 25°C		-1.1	-1.5		-1.1	-1.5		
I _{O(off)} OFF-State Open-Collector Output Current	V _{CC} = Max	V _{OH} = 12V	T _A = 25°C	1	100			μA	
			T _A = 125°C		200				
		V _{OH} = 5.25V	T _A = 25°C				1		100
			T _A = 70°C						200
I _I Input Current at Maximum Input Voltage	V _{CC} = Max, V _I = 5.5V			1			1	mA	
I _{IH} High Level Input Current	V _{CC} = Max, V _I = 2.4V			40			40	μA	
I _{IL} Low Level Input Current	V _{CC} = Max, V _I = 0.4V		-1.1	-1.6		-1.1	-1.6	mA	
I _{OS} Short-Circuit Output Current (Note 5)	V _{CC} = Max, V _O = 0	-40	-90	-120	-40	-90	-120	mA	
I _{CC} Supply Current (Both Drivers)	Inputs Grounded, No Load, T _A = 25°C	V _{CC} = Max	37	50	37	50		mA	
		V _{CC} = 7V	47	65	47	70			

Note 1: All voltage values are with respect to network ground terminal.

Note 2: For operation above 25°C free-air temperature, refer to Dissipation Derating Curves in the Thermal Information section.

Note 3: All parameters, with the exception of OFF-state open-collector output current, are measured with the active pull-up connected to the sink output.

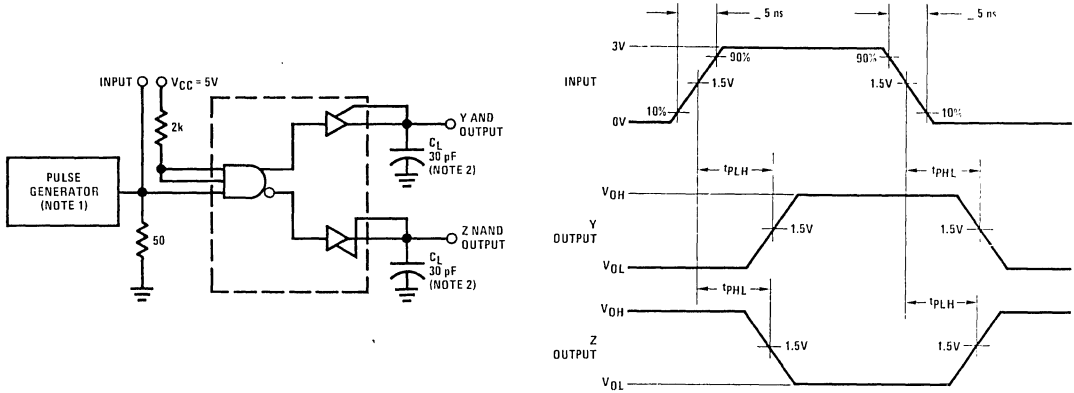
Note 4: All typical values are at T_A = 25°C and V_{CC} = 5V, with the exception of I_{CC} at 7V.

Note 5: Only one output should be shorted at a time, and duration of the short-circuit should not exceed one second.

Switching Characteristics V_{CC} = 5V, T_A = 25°C

PARAMETER	CONDITIONS	DS55114			DS75114			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
t _{PLH} Propagation Delay Time, Low-to-High-Level Output	C _L = 30 pF, (Figure 1)		15	20		15	30	ns
t _{PHL} Propagation Delay Time, High-to-Low-Level Output			11	20		11	30	ns

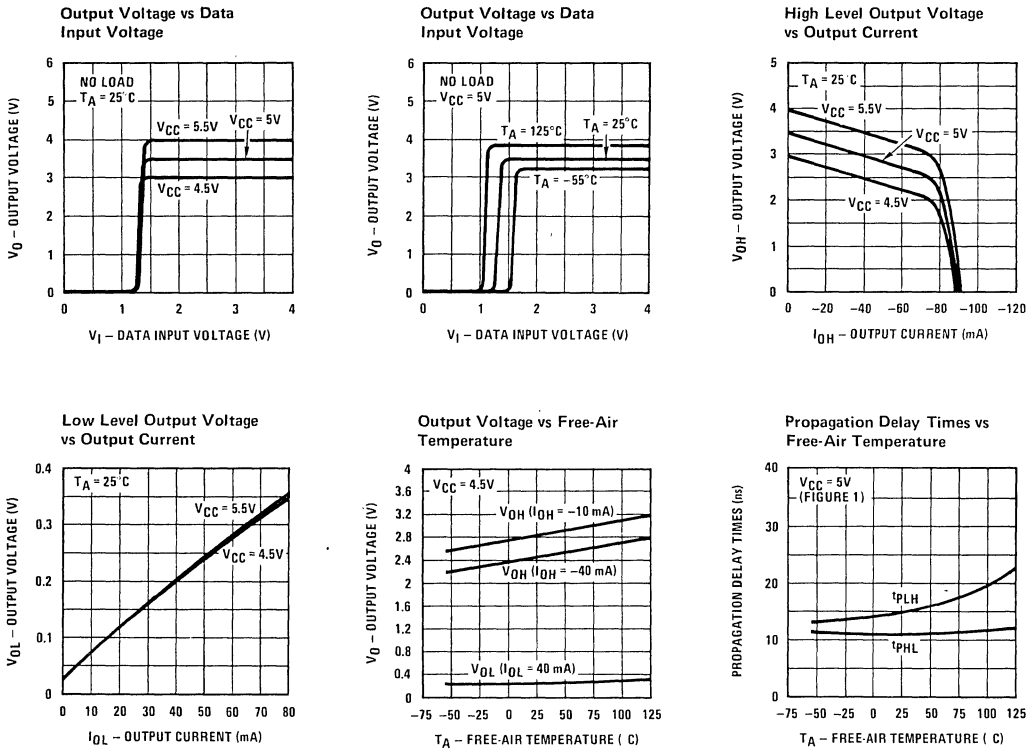
AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\Omega$, $t_W = 100$ ns, PRR = 500 kHz.
 Note 2: C_L includes probe and jig capacitance.

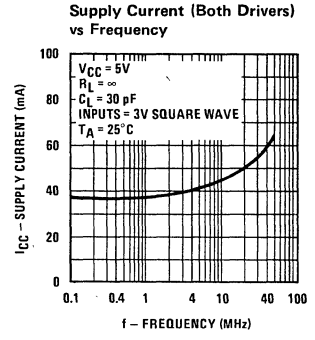
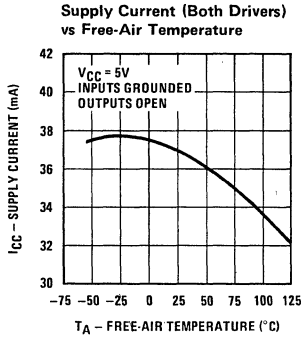
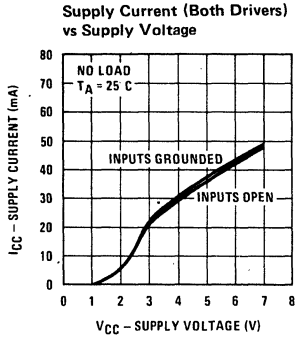
FIGURE 1

Typical Performance Characteristics



*Data for temperatures below 0°C and above 70°C and for supply voltages below 4.75V and above 5.25V are applicable to DS55114 circuits only. These parameters were measured with the active pull-up connected to the sink output.

Typical Performance Characteristics* (Continued)



*Data for temperatures below 0°C and above 70°C and for supply voltages below 4.75V and above 5.25V are applicable to DS55114 circuits only. These parameters were measured with the active pull-up connected to the sink output.

DS55115/DS75115 Dual Differential Line Receiver

General Description

The DS55115/DS75115 is a dual differential line receiver designed to sense differential signals from data transmission lines. Designed for operation over military and commercial temperature ranges, the DS55115/DS75115 can typically receive ± 500 mV differential data with ± 15 V common-mode noise. Outputs are open-collector and give TTL compatible signals which are a function of the polarity of the differential input signal. Active output pull-ups are also available, offering the option of an active TTL pull-up through an external connection.

Response time may be controlled with the use of an external capacitor. Each channel may be independently

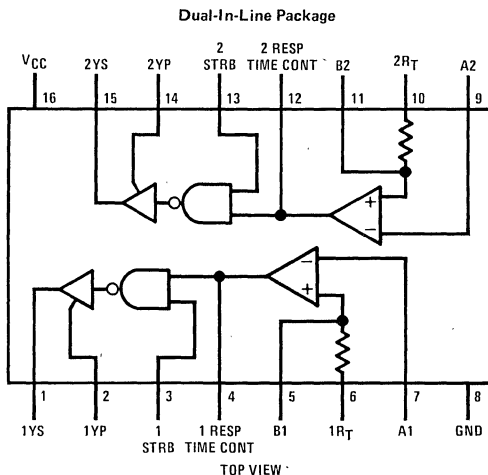
controlled and optional input termination resistors are also available.

Features

- Single 5V supply
- High common-mode voltage range
- Each channel individually strobed
- Independent time control
- Uncommitted collector or active pull-up option
- TTL compatible output
- Optional 130Ω termination resistors
- Direct replacement for 9615



Connection Diagram



Function Table

STROBE	DIFF. INPUT	OUTPUT
L	X	H
H	L	H
H	H	L

H = $V_I \geq V_{IH}$ min or V_{ID} more positive than V_{TH} max
 L = $V_I \leq V_{IL}$ max or V_{ID} more negative than V_{TL} max
 X = irrelevant

Order Number DS55115J, DS75115J or DS75115N
 See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage, V _{CC} (Note 1)	7V
Input Voltage at A, B and R _T Inputs	±25V
Input Voltage at Strobe Input	5.5V
Off-State Voltage Applied to Open-Collector Outputs	14V
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Operating Free-Air Temperature Range	
DS55115	-55°C to +125°C
DS75115	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (1/16 inch from case for 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, (V _{CC})			
DS55115	4.5	5.5	V
DS75115	4.75	5.25	V
High Level Output Current, (I _{OH})		-5	mA
Low Level Output Current, (I _{OL})		15	mA
Operating Temperature, (T _A)			
DS55115	-55	125	°C
DS75115	0	70	°C

Electrical Characteristics (Notes 2, 3 and 5)

PARAMETER	CONDITIONS	DS55115			DS75115			UNITS	
		MIN	TYP	MAX	MIN	TYP	MAX		
V _{TH}	Differential Input High-Threshold Voltage V _O = 0.4V, I _{OL} = 15 mA, V _{IC} = 0		200	500		200	500	mV	
V _{TL}	Differential Input Low-Threshold Voltage V _O = 2.4V, I _{OH} = -5 mA, V _{IC} = 0		-200	-500		-200	-500	mV	
V _{ICR}	Common-Mode Input Voltage Range V _{ID} = ±1V	15 to -15	24 to -19		15 to -15	24 to -19		V	
V _{IH(STROBE)}	High-Level Strobe Input Voltage	2.4			2.4			V	
V _{IL(STROBE)}	Low-Level Strobe Input Voltage			0.4			0.4	V	
V _{OH}	High Level Output Voltage V _{CC} = Min, V _{ID} = -0.5V, I _{OH} = -5 mA	T _A = Min 2.2	T _A = 25°C 2.4	T _A = Max 2.4	2.4	2.4	3.4	V	
V _{OL}	Low Level Output Voltage V _{CC} = Min, V _{ID} = 0.5V, I _{OL} = 15 mA		0.22	0.4		0.22	0.45	V	
I _{IL}	Low Level Input Current V _{CC} = Max, V _I = 0.4V, Other Input at 5.5V	T _A = Min		-0.9		-0.9		mA	
		T _A = 25°C	-0.5	-0.7	-0.5	-0.7			
		T _A = Max		-0.7		-0.7			
I _{SH}	High Level Strobe Current V _{CC} = Min, V _{ID} = -0.5V, V _{STROBE} = 4.5V	T _A = 25°C	0.5	2	0.5	5		μA	
		T _A = Max		5		10			
I _{SL}	Low Level Strobe Current V _{CC} = Max, V _{ID} = 0.5V, V _{STROBE} = 0.4V	T _A = 25°C	-1.15	-2.4	-1.15	-2.4		mA	
I _{4, I12}	Response Time Control Current (Pin 4 or Pin 12) V _{CC} = Max, V _{ID} = 0.5V, V _{RC} = 0	T _A = 25°C	-1.2	-3.4		-1.2	-3.4	mA	
I _{O(OFF)}	Off-State Open-Collector Output Current V _{CC} = Min, V _{OH} = 12V, V _{ID} = -4.5V	T _A = 25°C		100				μA	
	V _{CC} = Min, V _{OH} = 5.25V, V _{ID} = -4.75V	T _A = Max		200					
		T _A = 25°C				100			
		T _A = Max				200			
R _T	Line Terminating Resistance V _{CC} = 5V	T _A = 25°C	77	130	167	74	130	179	Ω
I _{OS}	Short-Circuit Output Current V _{CC} = Max, V _O = 0V, V _{ID} = -0.5V, (Note 4)	T _A = 25°C	-15	-40	-80	-14	-40	-100	mA
I _{CC}	Supply Current (Both Receivers) V _{CC} = Max, V _{ID} = 0.5V, V _{IC} = 0V	T _A = 25°C		32	50		32	50	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS55115 and across the 0°C to +70°C range for the DS75115. All typical values are for T_A = 25°C, V_{CC} = 5V and V_{CM} = 0V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

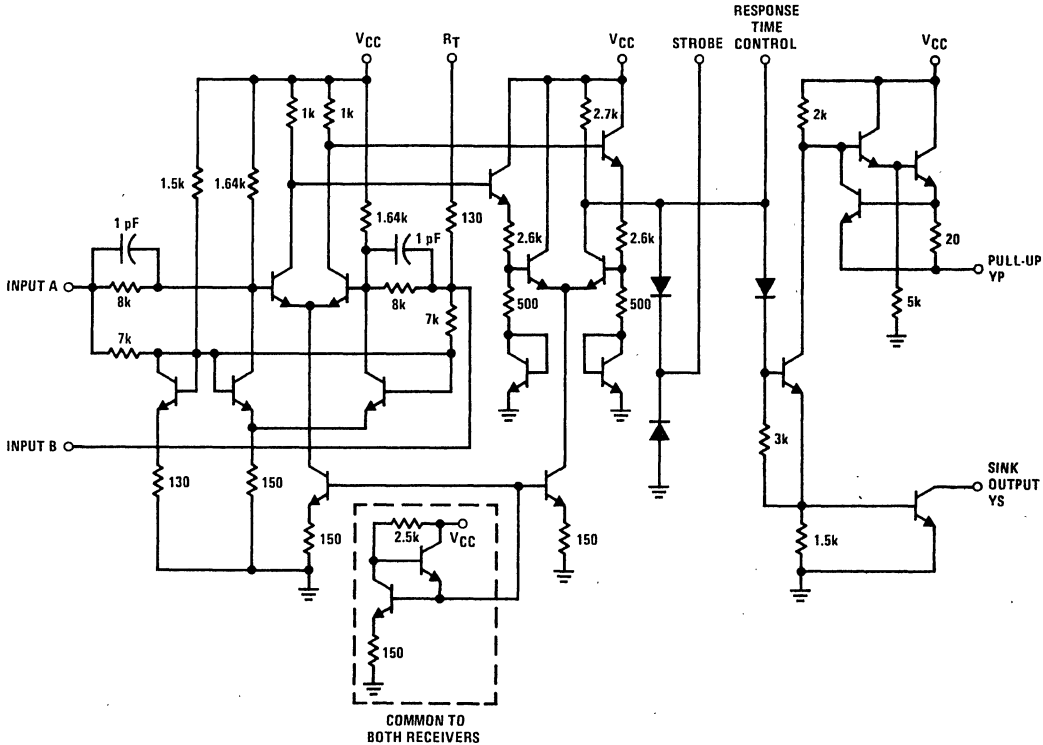
Note 5: Unless otherwise noted, V_{STROBE} = 2.4V. All parameters with the exception of off-state open-collector output current are measured with the active pull-up connected to the sink output.

Switching Characteristics $V_{CC} = 5V, C_L = 30\text{ pF}, T_A = 25^\circ\text{C}$

DS55115/DS75115

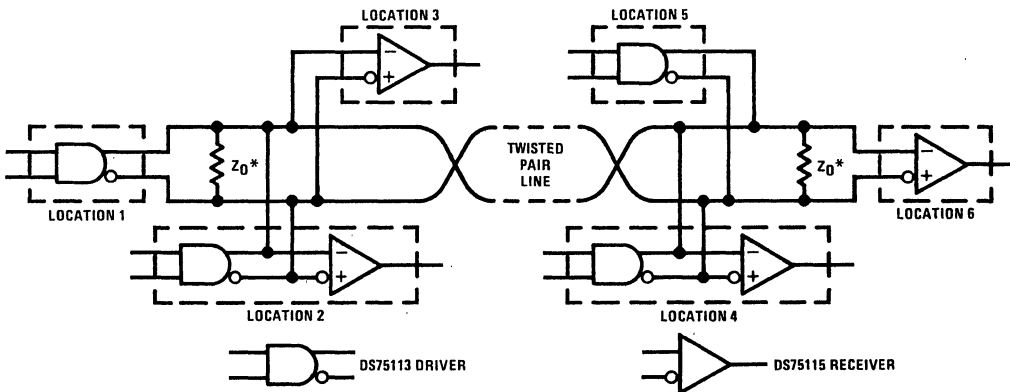
PARAMETER	CONDITIONS	DS55115			DS75115			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH} Propagation Delay Time, Low-to-High Level Output	$R_L = 3.9\text{ k}\Omega$, (Figure 1)		18	50		18	75	ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output	$R_L = 390\Omega$, (Figure 1)		20	50		20	75	ns

Schematic Diagram

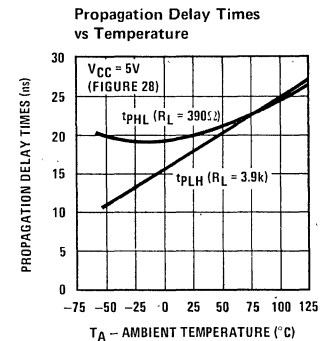
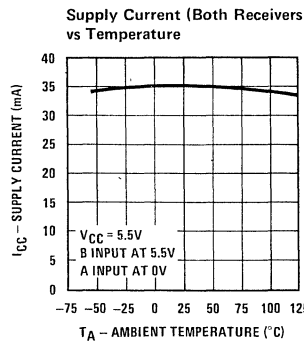
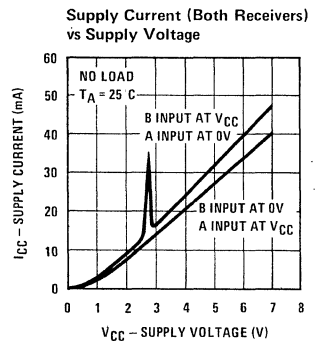
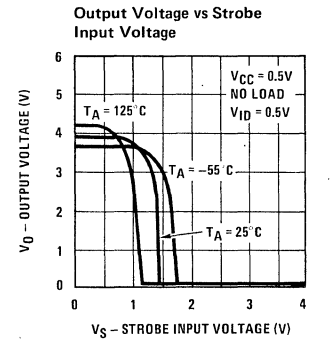
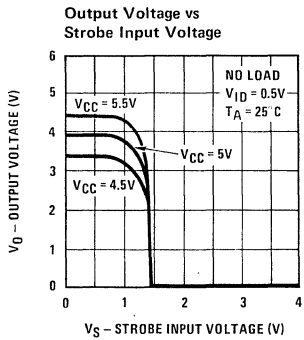
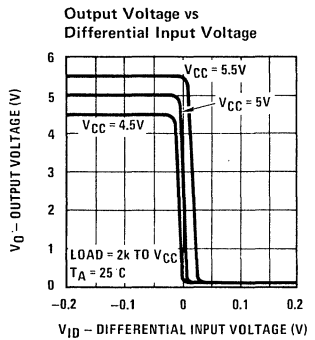
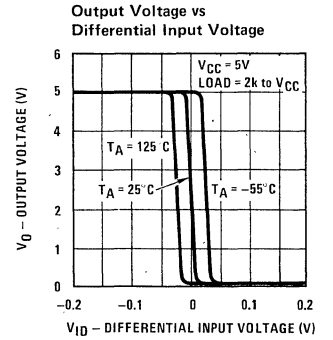
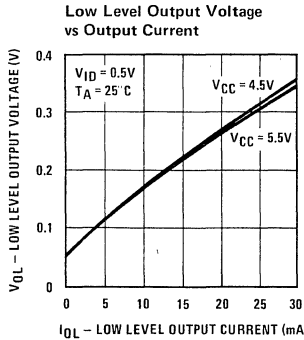
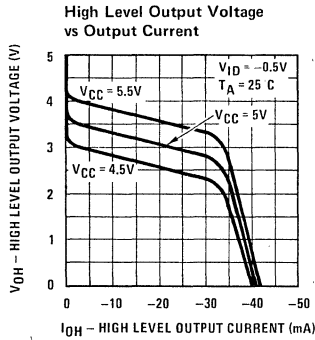
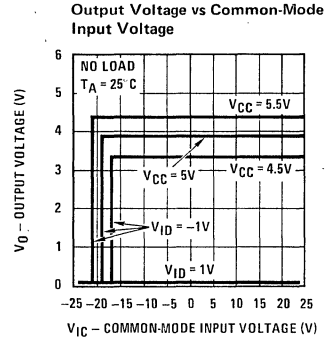
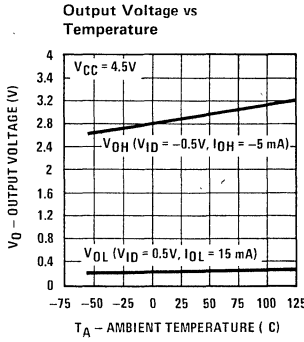
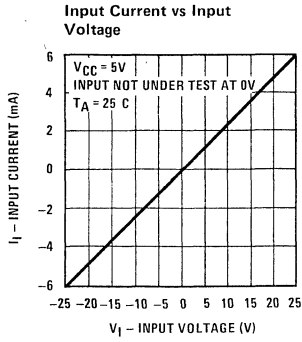


Typical Application

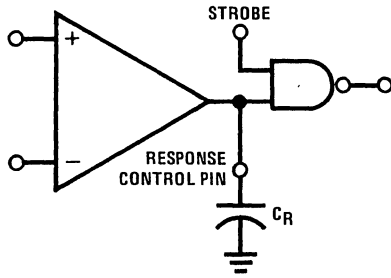
Basic Party-Line or Data-Bus Differential Data Transmission



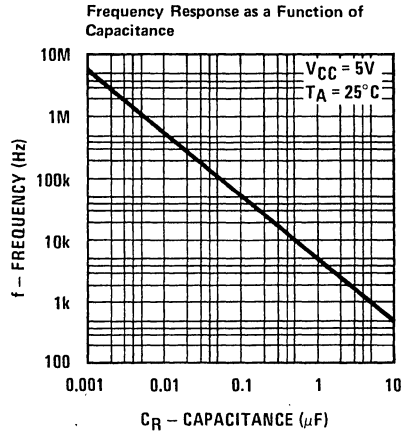
Typical Performance Characteristics (Note 3)



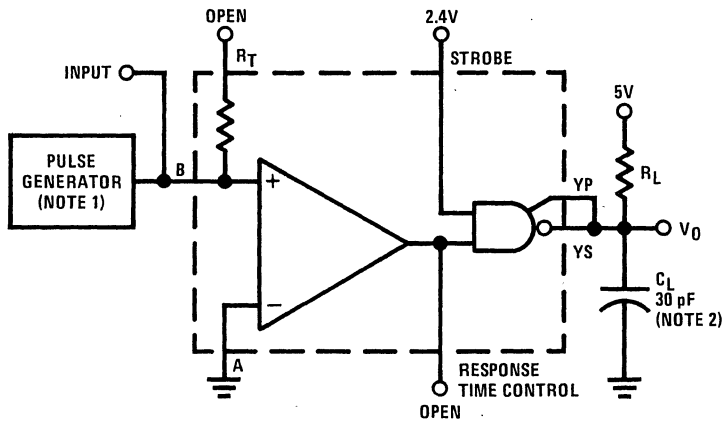
Frequency Response Control



Note. C_R (response control) $> 0.01 \mu F$ may cause slowing of rise and fall times of the output.



AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\Omega$, $PRR = 500 \text{ kHz}/t_w = 100 \text{ ns}$.

Note 2: C_L includes probe and test fixture capacitance.

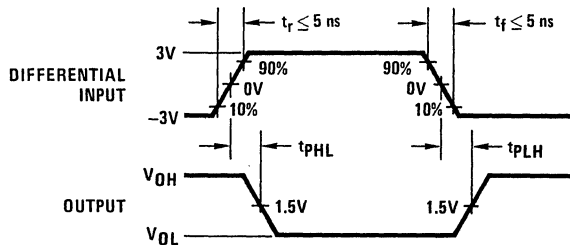


FIGURE 1. Propagation Delay Times

DS55121/DS75121 Dual Line Drivers

General Description

The DS55121/DS75121 are monolithic dual line drivers designed to drive long lengths of coaxial cable, strip line, or twisted pair transmission lines having impedances from 50 to 500 ohms. Both are compatible with standard TTL logic and supply voltage levels.

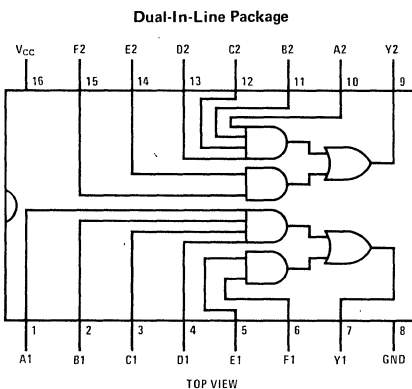
The DS55121/DS75121 will drive terminated low impedance lines due to the low-impedance emitter-follower outputs. In addition the outputs are uncommitted allowing two or more drivers to drive the same line.

Output short-circuit protection is incorporated to turn off the output when the output voltage drops below approximately 1.5V.

Features

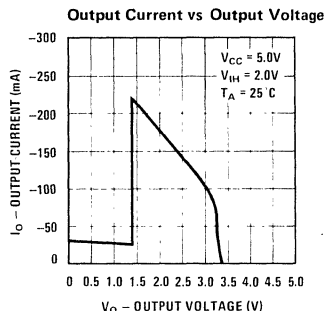
- Designed for digital data transmission over 50 to 500 ohms coaxial cable, strip line, or twisted pair transmission lines
- TTL compatible
- Open emitter-follower output structure for party-line operation
- Short-circuit protection
- AND-OR logic configuration
- High speed (max propagation delay time 20 ns)
- Plug-in replacement for the SN55121/SN75121 and the 8T13

Connection Diagram



Order Number DS55121J, DS75121J or DS75121N
See NS Package J16A or N16A

Typical Performance Characteristics

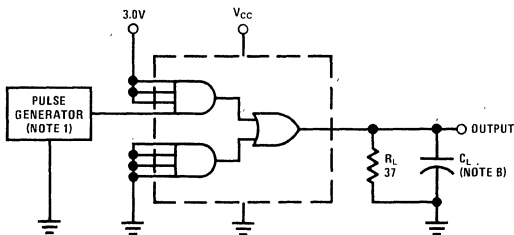


Truth Table

INPUTS						OUTPUT
A	B	C	D	E	F	Y
H	H	H	H	X	X	H
X	X	X	X	H	H	H
All Other Input Combinations						L

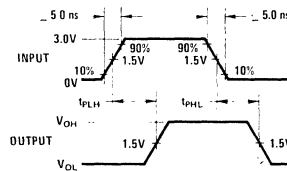
H = high level, L = low level, X = irrelevant

AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generators have the following characteristics:
 $Z_{OUT} \approx 50\Omega$, $t_w = 200$ ns, duty cycle = 50%, $t_r = t_f = 5$ ns.

Note 2: C_L includes probe and jig capacitance.



Absolute Maximum Ratings (Note 1)

Operating Conditions

		MIN	MAX	UNITS
Supply Voltage, V_{CC}	6.0V	4.75	5.25	V
Input Voltage	6.0V			
Output Voltage	6.0V			
Output Current	-75 mA	-55	+125	°C
Maximum Power Dissipation* at 25° C		0	+75	°C
Cavity Package	1371 mW			
Molded Package	1280 mW			
Lead Temperature (Soldering, 10 seconds)	300° C			

*Derate cavity package 9.1 mW/°C above 25° C; derate molded package 10.2 mW/°C above 25° C.

Electrical Characteristics $V_{CC} = 4.75V$ to $5.25V$ (unless otherwise noted) (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{IH}	High Level Input Voltage	2.0			V
V_{IL}	Low Level Input Voltage			0.8	V
V_I	Input Clamp Voltage	$V_{CC} = 5.0V, I_I = -12$ mA		-1.5	V
I_I	Input Current at Max Input Voltage	$V_{CC} = 5.25V, V_{IN} = 5.5V$		1	mA
V_{OH}	High Level Output Voltage	$V_{IH} = 2.0V, I_{OH} = -75$ mA (Note 4)	2.4		V
I_{OH}	High Level Output Current	$V_{CC} = 5.0V, V_{IH} = 4.75V, V_{OH} = 2.0V, T_A = 25^\circ C$ (Note 4)	-100	-250	mA
I_{OL}	Low Level Output Current	$V_{IL} = 0.8V, V_{OL} = 0.4V$ (Note 4)		-800	μA
$I_{O(OFF)}$	Off State Output Current	$V_{CC} = 0V, V_O = 3.0V$		500	μA
I_{IH}	High Level Input Current	$V_I = 4.5V$		40	μA
I_{IL}	Low Level Input Current	$V_I = 0.4V$	-0.1	-1.6	mA
I_{OS}	Short Circuit Output Current	$V_{CC} = 5.0V, T_A = 25^\circ C$		-30	mA
I_{CCH}	Supply Current, Outputs High	$V_{CC} = 5.25V$, All Inputs at 2.0V, Outputs Open		28	mA
I_{CCL}	Supply Current, Outputs Low	$V_{CC} = 5.25V$, All Inputs at 0.8V, Outputs Open		60	mA

Switching Characteristics $V_{CC} = 5.0V, T_A = 25^\circ C$

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{PLH}	Propagation Delay Time, Low-to-High Level Output $R_L = 37\Omega$, (See ac Test Circuit and Switching Time Waveforms)	$C_L = 15$ pF		11	20	ns
		$C_L = 1000$ pF		22	50	ns
t_{PHL}	Propagation Delay Time, High-to-Low Level Output $R_L = 37\Omega$, (See ac Test Circuit and Switching Time Waveforms)	$C_L = 15$ pF		8.0	20	ns
		$C_L = 1000$ pF		20	50	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55° C to +125° C temperature range for the DS55121 and across the 0° C to +70° C range for the DS75121. All typical values are for $T_A = 25^\circ C$ and $V_{CC} = 5V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: The output voltage and current limits are guaranteed for any appropriate combination of high and low inputs specified by the truth table for the desired output.

DS55122/DS75122 Triple Line Receivers

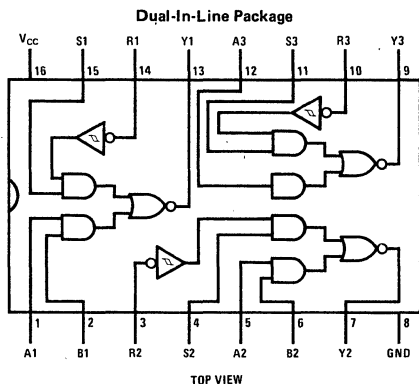
General Description

The DS55122/DS75122 are triple line receivers designed for digital data transmission with line impedances from 50Ω to 500Ω . Each receiver has one input with built-in hysteresis which provides a large noise margin. The other inputs on each receiver are in a standard TTL configuration. The DS55122/DS75122 are compatible with standard TTL logic and supply voltage levels.

Features

- Built-in input threshold hysteresis
- High speed ... typical propagation delay time 20 ns
- Independent channel strobes
- Input gating increases application flexibility
- Single 5.0V supply operation
- Fanout to 10 series 54/74 standard loads
- Plug-in replacement for the SN55122/SN75122 and the 8T14

Connection Diagram



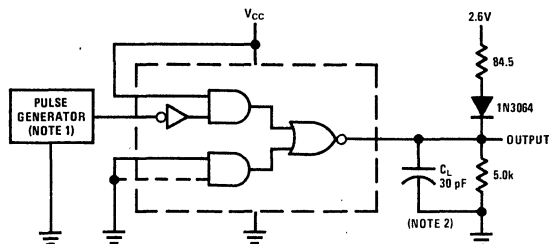
Order Number DS55122J, DS75122J or DS75122N
See NS Package J16A or N16A

Truth Table

INPUTS				OUTPUT
A	B†	R	S	Y
H	H	X	X	L
X	X	L	H	L
L	X	H	X	H
L	X	X	L	H
X	L	H	X	H
X	L	X	L	H

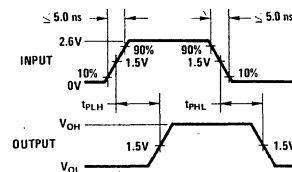
H = high level, L = low level, X = irrelevant
†B input and last two lines of the truth table are applicable to receivers 1 and 2 only.

AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics:
 $Z_{OUT} \approx 50\Omega$, $t_W = 200$ ns, duty cycle = 50%, $t_r = t_f = 5.0$ ns.

Note 2: C_L includes probe and jig capacitance.



Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	6.0V
Input Voltage	
R Input	6.0V
A, B, or S Input	5.5V
Output Voltage	6.0V
Output Current	+100 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}	4.75	5.25	V
Operating Temperature, T_A			
DS55122	-55	+125	°C
DS75122	0	+75	°C
High Level Output Current, I_{OH}		-500	μA
Low Level Output Current, I_{OL}		16	mA

Electrical Characteristics $V_{CC} = 4.75V$ to $5.25V$ (unless otherwise noted) (Notes 2 and 3)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
V_{IH}	High Level Input Voltage	A, B, R, or S	2.0			V
V_{IL}	Low Level Input Voltage	A, B, R, or S			0.8	V
$V_{T+} - V_{T-}$	Hysteresis	$V_{CC} = 5.0V$, $T_A = 25^\circ C$, R, (Note 6)	0.3	0.6		V
V_I	Input Clamp Voltage	$V_{CC} = 5.0V$, $I_I = -12$ mA, A, B, or S			-1.5	V
I_I	Input Current at Max Input Voltage	$V_{CC} = 5.25V$, $V_{IN} = 5.5V$, A, B, or S			1.0	mA
V_{OH}	High Level Output Voltage	$I_{OH} = -500\mu A$	$V_{IH} = 2V$, $V_{IL} = 0.8V$, (Note 4)	2.6		V
			$V_{I(A)} = 0V$, $V_{I(B)} = 0V$, $V_{I(R)} = 1.45V$, $V_{I(S)} = 2.0V$, (Note 7)	2.6		V
V_{OL}	Low Level Output Voltage	$I_{OL} = 16$ mA	$V_{IH} = 2.0V$, $V_{IL} = 0.8V$, (Note 4)		0.4	V
			$V_{I(A)} = 0V$, $V_{I(B)} = 0V$, $V_{I(R)} = 1.45V$, $V_{I(S)} = 2.0V$, (Note 8)		0.4	V
I_{IH}	High Level Input Current	$V_I = 4.5V$, A, B, or S			40	μA
		$V_I = 3.8V$, R			170	μA
I_{IL}	Low Level Input Current	$V_I = 0.4V$, A, B, or S	0.1		-1.6	mA
I_{OS}	Short Circuit Output Current	$V_{CC} = 5.0V$, $T_A = 25^\circ C$, (Note 5)	-50		-100	mA
I_{CC}	Supply Current	$V_{CC} = 5.25V$			72	mA

Switching Characteristics $V_{CC} = 5.0V$, $T_A = 25^\circ C$

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
t_{PLH}	Propagation Delay Time, Low-to-High Level Output from R Input	(See ac Test Circuit and Switching Time Waveforms)		20	30	ns
t_{PHL}	Propagation Delay Time, High-to-Low Level Output from R Input	(See ac Test Circuit and Switching Time Waveforms)		20	30	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All currents into device pins are shown as positive, currents out of device pins shown as negative, all voltage values are referenced with respect to network ground terminal, unless otherwise noted. All values shown as max or min on absolute value basis.

Note 3: Min/max limits apply across the guaranteed operating temperature range of -55°C to +125°C for DS55122 and 0°C to +75°C for DS75122, unless otherwise specified. Typicals are for $V_{CC} = 5.0V$, $T_A = 25^\circ C$. Positive current is defined as current into the referenced pin.

Note 4: The output voltage and current limits are guaranteed for any appropriate combination of high and low inputs specified by the truth table for the desired output.

Note 5: Not more than one output should be shorted at a time.

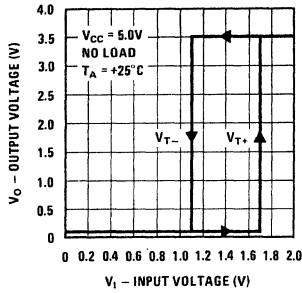
Note 6: Hysteresis is the difference between the positive going input threshold voltage, V_{T+} , and the negative going input threshold voltage, V_{T-} .

Note 7: Receiver input was at a high level immediately before being reduced to 1.45V.

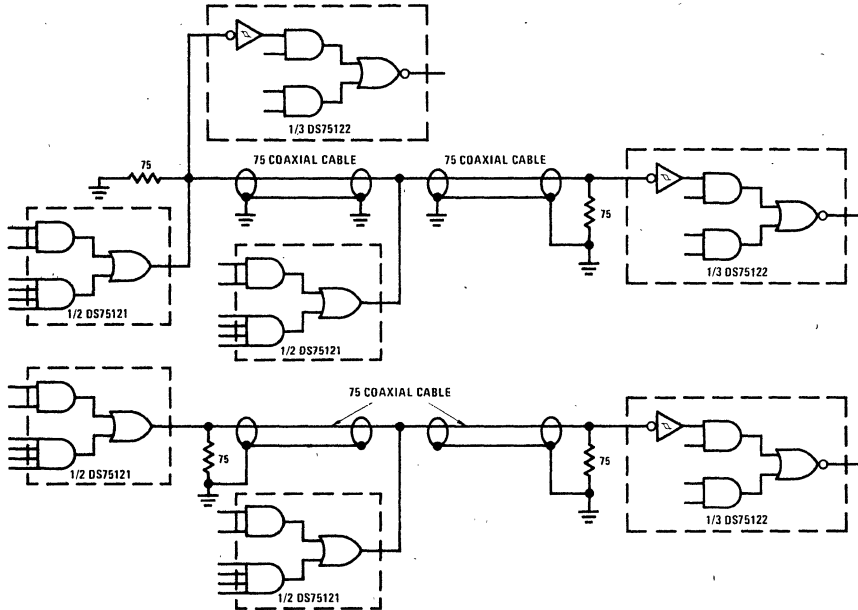
Note 8: Receiver input was at a low level immediately before being raised to 1.45V.

Typical Performance Characteristics

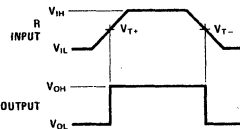
Output Voltage vs Receiver Input Voltage



Typical Applications



Single-Ended Party Line Circuits



The high gain and built-in hysteresis of the DS55122/DS75122 line receivers enable them to be used as Schmitt triggers in squaring up pulses.

Pulse Squaring

DS75123 Dual Line Driver

General Description

The DS75123 is a monolithic dual line driver designed specifically to meet the I/O interface specifications for IBM System 360. It is compatible with standard TTL logic and supply voltage levels.

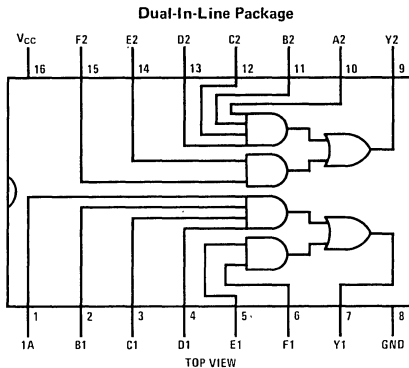
The low-impedance emitter-follower outputs of the DS75123 enable driving terminated low impedance lines. In addition the outputs are uncommitted allowing two or more drivers to drive the same line.

Output short-circuit protection is incorporated to turn off the output when the output voltage drops below approximately 1.5V.

Features

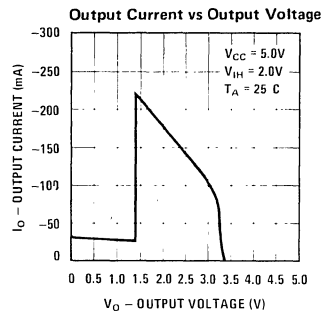
- Meet IBM System 360 I/O interface specifications for digital data transmission over 50Ω to 500Ω coaxial cable, strip line, or terminated pair transmission lines
- TTL compatible with single 5.0V supply
- 3.11V output at $I_{OH} = -59.3 \text{ mA}$
- Open emitter-follower output structure for party-line operation
- Short circuit protection
- AND-OR logic configuration
- Plug-in replacement for the SN75123 and the 8T23

Connection Diagram



Order Number DS75123J or DS75123N
See NS Package J16A or N16A

Typical Performance Characteristics

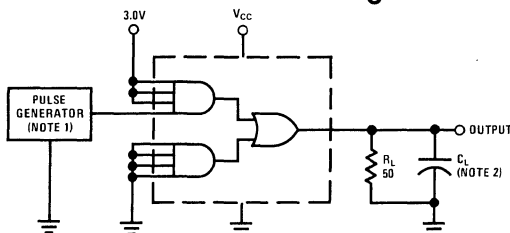


Truth Table

INPUTS						OUTPUT
A	B	C	D	E	F	Y
H	H	H	H	X	X	H
X	X	X	X	H	H	H
All Other Input Combinations						L

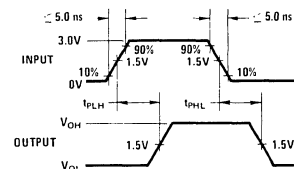
H = high level, L = low level, X = irrelevant

AC Test Circuit and Switching Time Waveforms



Note 1: THE PULSE GENERATORS HAVE THE FOLLOWING CHARACTERISTICS: $Z_{OUT} = 50\Omega$, $t_{pw} = 200 \text{ ns}$, DUTY CYCLE = 50%.

Note 2: C_L INCLUDES PROBE AND JIG CAPACITANCE.



Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Output Voltage	7.0V
Maximum Power Dissipation* at 25°C	
Cavity Package	1371 mW
Molded Package	1280 mW
Operating Free-Air Temperature Range	0°C to +75°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.1 mW/°C above 25°C; derate molded package 10.2 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}	4.75	5.25	V
High Level Output Current, I_{OH}		-100	mA
Temperature, T_A	0	+75	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{IH}	High Level Input Voltage	2.0			V
V_{IL}	Low Level Input Voltage			0.8	V
V_I	Input Clamp Voltage	$V_{CC} = 5.0V, I_I = -12 mA$		-1.5	V
I_I	Input Current at Max Input Voltage	$V_{CC} = 5.25V, V_{IN} = 5.5V$		1	mA
V_{OH}	High Level Output Voltage	$V_{CC} = 5.0V, V_{IH} = 2.0V,$	$T_A = 25^\circ C$	3.11	V
		$I_{OH} = -59.3 mA, (Note 4)$	$T_A = 0^\circ C \text{ to } +75^\circ C$	2.9	V
I_{OH}	High Level Output Current	$V_{CC} = 5.0V, V_{IH} = 4.5V, T_A = 25^\circ C,$ $V_{OH} = 2.0V, (Note 4)$		-100	mA
V_{OL}	Low Level Output Voltage	$V_{IL} = 0.8V, I_{OL} = -240\mu A, (Note 4)$		0.15	V
$I_{O(OFF)}$	Off State Output Current	$V_{CC} = 0, V_O = 3.0V$		40	μA
I_{IH}	High Level Input Current	$V_I = 4.5V$		40	μA
I_{IL}	Low Level Input Current	$V_I = 0.4V$	-0.1	-1.6	mA
I_{OS}	Short Circuit Output Current	$V_{CC} = 5.0V, T_A = 25^\circ C$		-30	mA
I_{CCH}	Supply Current, Outputs High	$V_{CC} = 5.25V, \text{All Inputs at } 2.0V, \text{Outputs Open}$		28	mA
I_{CCL}	Supply Current, Outputs Low	$V_{CC} = 5.25V, \text{All Inputs at } 0.8V, \text{Outputs Open}$		60	mA

Switching Characteristics $V_{CC} = 5.0V, T_A = 25^\circ C$

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{PLH}	Propagation Delay Time, Low-to-High Level Output	$R_L = 50\Omega, (See \text{ ac Test Circuit and Switching Time Waveforms})$	$C_L = 15 pF$	12	20	ns
			$C_L = 100 pF$	20	35	ns
t_{PHL}	Propagation Delay Time, High-to-Low Level Output	$R_L = 50\Omega, (See \text{ ac Test Circuit and Switching Time Waveforms})$	$C_L = 15 pF$	12	20	ns
			$C_L = 100 pF$	15	25	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All currents into device pins are shown as positive, currents out of device pins shown as negative, all voltage values are referenced with respect to network ground terminal, unless otherwise noted. All values shown as max or min on absolute value basis.

Note 3: Min/max limits apply across the guaranteed operating temperature range of 0°C to +75°C for DS75123, unless otherwise specified. Typicals are for $V_{CC} = 5.0V, T_A = 25^\circ C$. Positive current is defined as current into the referenced pin.

Note 4: The output voltage and current limits are guaranteed for any appropriate combination of high and low inputs specified by the truth table for the desired output.

DS75124 Triple Line Receiver

General Description

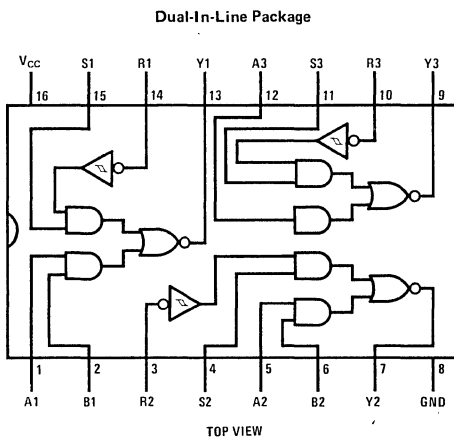
The DS75124 is designed to meet the input/output interface specifications for IBM System 360. It has built-in hysteresis on one input on each of the three receivers to provide large noise margin. The other inputs on each receiver are in a standard TTL configuration. The DS75124 is compatible with standard TTL logic and supply voltage levels.

Features

- Built-in input threshold hysteresis
- High speed . . . typ propagation delay time 20 ns
- Independent channel strobes
- Input gating increases application flexibility
- Single 5.0V supply operation
- Plug-in replacement for the SN75124 and the 8T24

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Connection Diagram and Truth Table

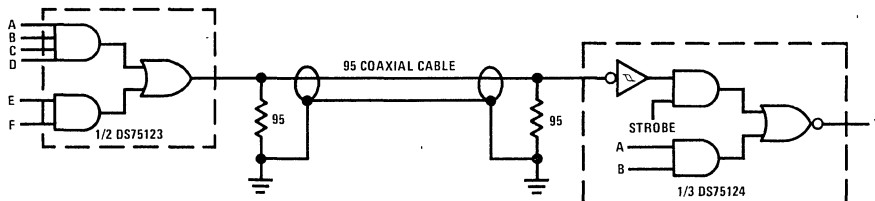


INPUTS				OUTPUT
A	B†	R	S	Y
H	H	X	X	L
X	X	L	H	L
L	X	H	X	H
L	X	X	L	H
X	L	H	X	H
X	L	X	L	H

H = high level, L = low level, X = irrelevant
 †B input and last two lines of the truth table are applicable to receivers 1 and 2 only.

Order Number DS75124J or DS75124N
 See NS Package J16A or N16A

Typical Application



Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	
R Input with V_{CC} Applied	7.0V
R Input with V_{CC} not Applied	6.0V
A, B, or S Input	5.5V
Output Voltage	7.0V
Output Current	±100 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Operating Temperature Range	0°C to +75°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}	4.75	5.25	V
High Level Output Current, I_{OH}		-800	μA
Low Level Output Current, I_{OL}		16	mA
Operating Temperature, T_A	0	+75	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{IH} High Level Input Voltage	A, B, or S	2.0			V
	R	1.7			V
V_{IL} Low Level Input Voltage	A, B, or S			0.8	V
	R			0.7	V
$V_{T+} - V_{T-}$ Hysteresis	$V_{CC} = 5.0V$, $T_A = 25^\circ C$, R, (Note 6)	0.2	0.4		V
V_I Input Clamp Voltage	$V_{CC} = 5.0V$, $I_I = -12$ mA, A, B, or S			-1.5	V
I_I Input Current at Maximum Input Voltage	$V_{CC} = 5.25V$, $V_{IN} = 5.5V$, A, B, or S			1	mA
	R			5.0	mA
	$V_I = 6.0V$, $V_{CC} = 0$			5.0	mA
V_{OH} High Level Output Voltage	$V_{IH} = V_{IHMIN}$, $V_{IL} = V_{ILMAX}$, $I_{OH} = -800\mu A$, (Note 4)	2.6			V
V_{OL} Low Level Output Voltage	$V_{IH} = V_{IHMIN}$, $V_{IL} = V_{ILMAX}$, $I_{OL} = 16$ mA, (Note 4)			0.4	V
I_{IH} High Level Input Current	$V_I = 4.5V$, A, B, or S			40	μA
	$V_I = 3.11V$, R			170	μA
I_{IL} Low Level Input Current	$V_I = 0.4V$, A, B, or S	-0.1		-1.6	mA
I_{OS} Short Circuit Output Current	$V_{CC} = 5.0V$, $T_A = 25^\circ C$, (Note 5)	-50		-100	mA
I_{CC} Supply Current	$V_{CC} = 5.25V$			72	mA

Switching Characteristics $T_A = 25^\circ C$, nominal power supplies unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-to-High Level Output from R Input	(See ac Test Circuit and Switching Time Waveforms)		20	30	ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output from R Input	(See ac Test Circuit and Switching Time Waveforms)		20	30	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All currents into device pins are shown as positive, currents out of device pins shown as negative, all voltage values are referenced with respect to network ground terminal, unless otherwise noted. All values shown as max or min on absolute value basis.

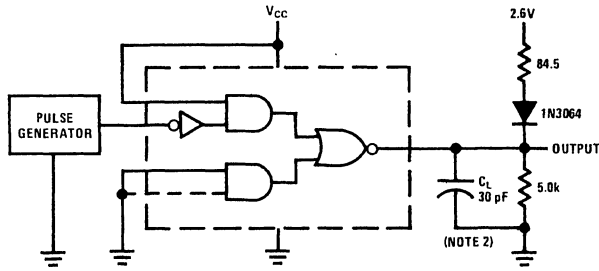
Note 3: Min/max limits apply across the guaranteed operating temperature range of 0°C to +75°C for DS75124, unless otherwise specified. Typicals are for $V_{CC} = 5.0V$, $T_A = 25^\circ C$. Positive current is defined as current into the referenced pin.

Note 4: The output voltage and current limits are guaranteed for any appropriate combination of high and low inputs specified by the truth table for the desired output.

Note 5: Not more than one output should be shorted at a time.

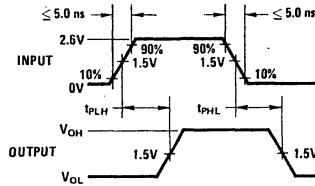
Note 6: Hysteresis is the difference between the positive going input threshold voltage, V_{T+} , and the negative going input threshold voltage, V_{T-} .

AC Test Circuit and Switching Time Waveforms

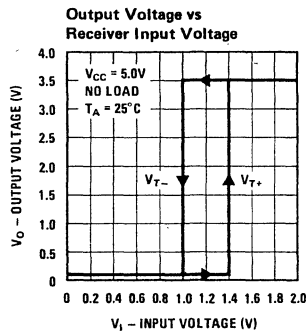


Note 1: THE PULSE GENERATOR HAS THE FOLLOWING CHARACTERISTICS: $Z_{OUT} \approx 50\Omega$, $t_w = 200$ ns, DUTY CYCLE = 50%.

Note 2: C_L INCLUDES PROBE AND JIG CAPACITANCE.



Typical Performance Characteristics



DS75125, DS75127 Seven-Channel Line Receivers

General Description

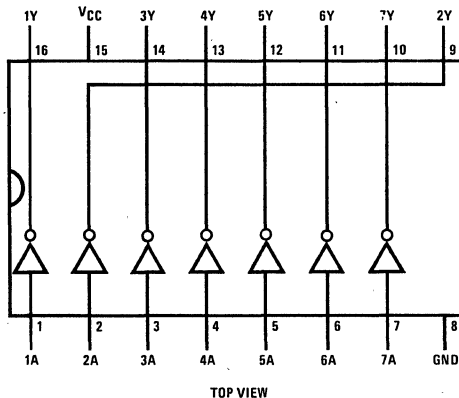
The DS75125 and DS75127 are monolithic seven-channel line receivers designed to satisfy the requirements of the IBM System 360/370 input/output interface specifications. Special low-power design and Schottky clamped transistors allow for low supply current requirements while maintaining fast switching speeds and high current TTL outputs. The DS75125 and DS75127 are characterized for operation from 0°C to 70°C.

Features

- Meets IBM 360/370 I/O specification
- Input resistance—7 k Ω to 20 k Ω
- Output compatible with TTL
- Schottky-clamped transistors
- Operates from single 5V supply
- High speed—low propagation delay
- Ratio specification for propagation delay time, low-to-high/high-to-low
- Seven channels in one 16-pin package
- Standard V_{CC} and ground positioning on DS75127

Connection Diagrams

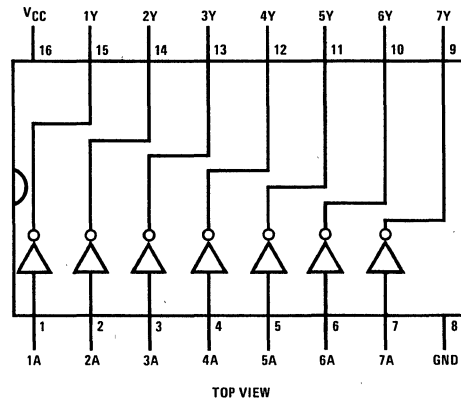
DS75125
Dual-In-Line Package



logic: $Y = \bar{A}$

Order Number DS75125J or DS75125N
See NS Package J16A or N16A

DS75127
Dual-In-Line Package



logic: $Y = \bar{A}$

Order Number DS75127J or DS75127N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC} (Note 1)	7V
Input Voltage Range	
DS75125	-0.15V to 7V
DS75127	-2V to 7V
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Operating Free-Air Temperature Range	0°C to 70°C
Storage Temperature Range	-65°C to 150°C
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.9 mW/°C above 25°C.

Recommended Operating Conditions

	Min	Typ	Max	Units
Supply Voltage, V_{CC}	4.5	5	5.5	V
High-Level Output Current, I_{OH}			-0.4	mA
Low-Level Output Current, I_{OL}			16	mA
Operating Free-Air Temperature, T_A	0		70	°C

Electrical Characteristics over recommended operating free-air temperature range (Note 3)

Parameter	Conditions	Min	Typ (Note 5)	Max	Units
V_{IH} High-Level Input Voltage		1.7			V
V_{IL} Low-Level Input Voltage				0.7	V
V_{OH} High-Level Output Voltage	$V_{CC} = 4.5V$, $V_{IL} = 0.7V$, $I_{OH} = -0.4$ mA	2.4	3.1		V
V_{OL} Low-Level Output Voltage	$V_{CC} = 4.5V$, $V_{IH} = 1.7V$, $I_{OL} = 16$ mA		0.4	0.5	V
I_{IH} High-Level Input Current	$V_{CC} = 5.5V$, $V_I = 3.11V$		0.3	0.42	mA
I_{IL} Low-Level Input Current	$V_{CC} = 5.5V$, $V_I = 0.15V$			-0.24	mA
I_{OS} Short-Circuit Output Current (Note 4)	$V_{CC} = 5.5V$, $V_O = 0$	-18		-60	mA
r_i Input Resistance	$V_{CC} = 4.5V$, 0V, or Open, $\Delta V_I = 0.15V$ to 4.15V	7		20	k Ω
I_{CC} Supply Current	$V_{CC} = 5.5V$, $I_{OH} = -0.4$ mA, All Inputs at 0.7V		15	25	mA
	$V_{CC} = 5.5V$, $I_{OL} = 16$ mA, All Inputs at 4V		28	47	mA

Switching Characteristics $V_{CC} = 5V$, $T_A = 25^\circ C$

Parameter	Conditions	Min	Typ	Max	Units
t_{PLH} Propagation Delay Time, Low-to-High-Level Output	$R_L = 400\Omega$, $C_L = 50$ pF, See Figure 1	7	14	25	ns
t_{PHL} Propagation Delay Time, High-to-Low-Level Output		10	18	30	ns
$\frac{t_{PLH}}{t_{PHL}}$ Ratio of Propagation Delay Times		0.5	0.8	1.3	ns
t_{TLH} Transition Time, Low-to-High-Level Output		1	7	12	ns
t_{THL} Transition Time, High-to-Low-Level Output		1	3	12	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

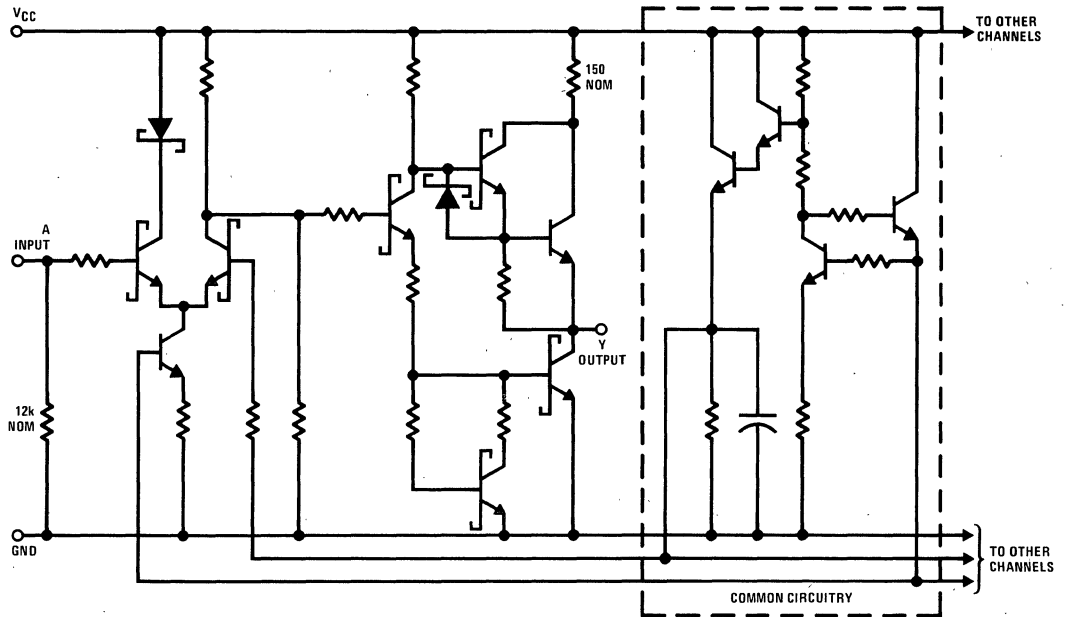
Note 2: For operation above 25°C free-air temperature, refer to Thermal Ratings for ICs in Section 12 of Interface Databook.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

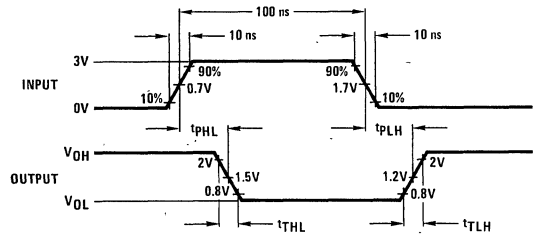
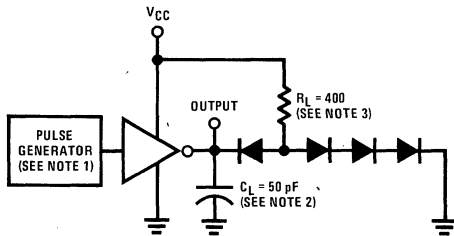
Note 4: Only one output should be shorted at a time.

Note 5: All typical values are at $V_{CC} = 5V$, $T_A = 25^\circ C$.

Schematic (each receiver)



AC Test Circuit and Switching Time Waveforms

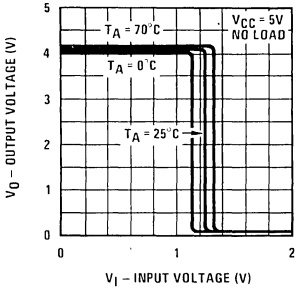


- Note 1: The pulse generator has the following characteristics: $Z_{OUT} \approx 50\Omega$, PRR = 5 MHz.
- Note 2: C_L includes probe and jig capacitance.
- Note 3: All diodes are 1N3064 or equivalent.

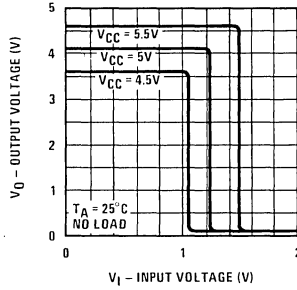
FIGURE 1

Typical Performance Characteristics

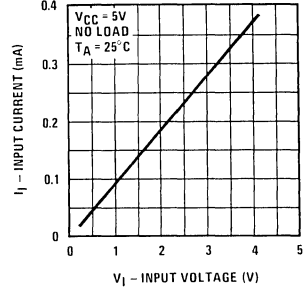
Voltage Transfer Characteristics



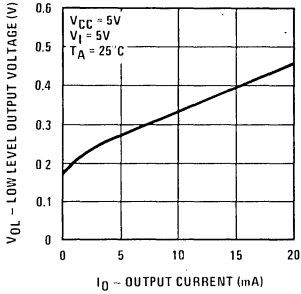
Voltage Transfer Characteristics



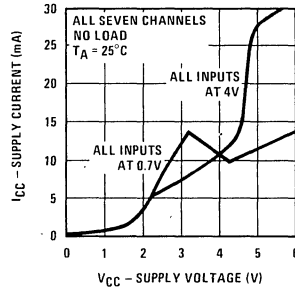
Input Current vs Input Voltage



Low-Level Output Voltage vs Output Current



Supply Current vs Supply Voltage



DS75128, DS75129 Eight-Channel Line Receivers

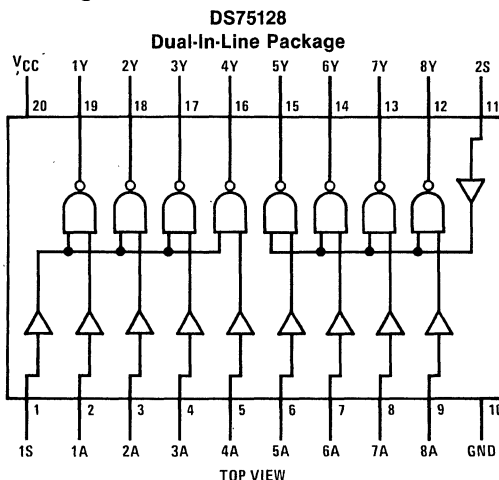
General Description

The DS75128 and DS75129 are eight-channel line receivers designed to satisfy the requirements of the input-output interface specification for IBM 360/370. Both devices feature common strobes for each group of four receivers. The DS75128 has an active-high strobe; the DS75129 has an active-low strobe. Special low-power design and Schottky-diode-clamped transistors allow low supply-current requirements while maintaining fast switching speeds and high-current TTL outputs. The DS75128 and DS75129 are characterized for operation from 0°C to 70°C.

Features

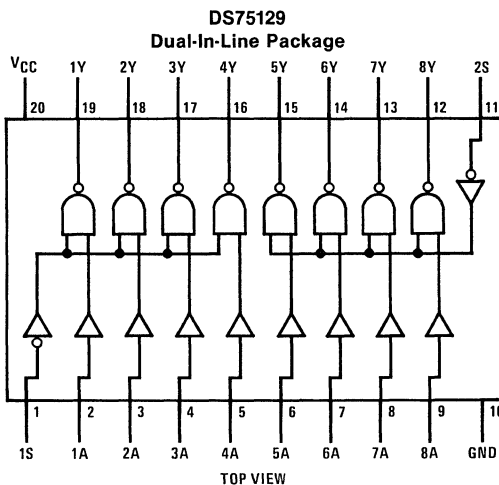
- Meets IBM 360/370 I/O specification
- Input resistance — 7 kΩ to 20 kΩ
- Output compatible with TTL
- Schottky-clamped transistors
- Operates from a single 5V supply
- High speed — low propagation delay
- Ratio specification — t_{PLH}/t_{PHL}
- Common strobe for each group of four receivers
- DS75128 strobe — active-high
DS75129 strobe — active-low

Connection Diagrams



positive logic: $Y = AS$

Order Number DS75128J or DS75128N
See NS Package J20A or N20A



positive logic: $Y = \overline{AS}$

Order Number DS75129J or DS75129N
See NS Package J20A or N20A

Absolute Maximum Ratings over operating free-air temperature range (unless otherwise noted)

Supply Voltage, V_{CC} (Note 1)	7V
A Input Voltage Range	-0.15V to 7V
Strobe Input Voltage	7V
Maximum Power Dissipation* at 25°C	
Cavity Package	1564 mW
Molded Package	1687 mW
Operating Free-Air Temperature Range	0°C to 70°C
Storage Temperature Range	-65°C to 150°C
Lead Temperature	300°C
1/16 inch from Case for 60 Seconds: J Package	
Lead Temperature	260°C
1/16 inch from Case for 10 Seconds: N Package	

* Derate cavity package 10.4 mW/°C above 25°C; derate molded package 13.5 mW/°C above 25°C.

Recommended Operating Conditions

	Min	Typ	Max	Units
Supply Voltage, V_{CC}	4.5	5.0	5.5	V
High-Level Output Current, I_{OH}			-0.4	mA
Low-Level Output Current, I_{OL}			16	mA
Operating Free-Air Temperature, T_A	0		70	°C

Electrical Characteristics over recommended operating free-air temperature range (Note 3)

Parameter		Conditions	Min	Typ (Note 5)	Max	Units
V_{IH} High-Level Input Voltage	A		1.7			V
	S		2			
V_{IL} Low-Level Input Voltage	A				0.7	V
	S				0.7	
V_{OH} High-Level Output Voltage		$V_{CC} = 4.5V, V_{IL} = 0.7V, I_{OH} = -0.4 mA$	2.4	3.1		V
V_{OL} Low-Level Output Voltage		$V_{CC} = 4.5V, V_{IH} = 1.7V, I_{OL} = 16 mA$		0.4	0.5	V
V_I Input Clamp Voltage	S	$V_{CC} = 4.5V, I_I = -18 mA$			-1.5	V
I_{IH} High-Level Input Current	A	$V_{CC} = 5.5V, V_I = 3.11V$		0.3	0.42	mA
	S	$V_{CC} = 5.5V, V_I = 2.7V$			20	μA
I_{IL} Low-Level Input Current	A	$V_{CC} = 5.5V, V_I = 0.15V$			-0.24	mA
	S	$V_{CC} = 5.5V, V_I = 0.4V$			-0.4	
I_{OS} Short-Circuit Output Current (Note 4)		$V_{CC} = 5.5V, V_O = 0$	-18		-60	mA
r_I Input Resistance		$V_{CC} = 4.5V, 0V, \text{ or Open}, \Delta V_I = 0.15V \text{ to } 4.15V$	7		20	kΩ
I_{CC} Supply Current	DS75128	$V_{CC} = 5.5V, \text{ Strobe at } 2.4V, \text{ All A Inputs at } 0.7V$		19	31	mA
	DS75129	$V_{CC} = 5.5V, \text{ Strobe at } 0.4V, \text{ All A Inputs at } 0.7V$		19	31	
	DS75128	$V_{CC} = 5.5V, \text{ Strobe at } 2.4V, \text{ All A Inputs at } 4V$		32	53	
	DS75129	$V_{CC} = 5.5V, \text{ Strobe at } 0.4V, \text{ All A Inputs at } 4V$		32	53	

Switching Characteristics $V_{CC} = 5V, T_A = 25^\circ C$

Parameter	Conditions	DS75128			DS75129			Units
		Min	Typ	Max	Min	Typ	Max	
t_{PLH} Propagation Delay Time, Low-to-High-Level Output	$R_L = 400\Omega,$ $C_L = 50 pF,$	7	14	25	7	14	25	ns
t_{PHL} Propagation Delay Time, High-to-Low-Level Output		10	18	30	10	18	30	
t_{PLH} Propagation Delay Time, Low-to-High-Level Output		26	40		20	35		
t_{PHL} Propagation Delay Time, High-to-Low-Level Output		22	35		16	30		
$\frac{t_{PLH}}{t_{PHL}}$ Ratio of Propagation Delay Times	A	0.5	0.8	1.3	0.5	0.8	1.3	
t_{TLH} Transition Time, Low-to-High-Level Output	See Figure 1	1	7	12	1	7	12	ns
t_{THL} Transition Time, High-to-Low-Level output		1	3	12	1	3	12	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

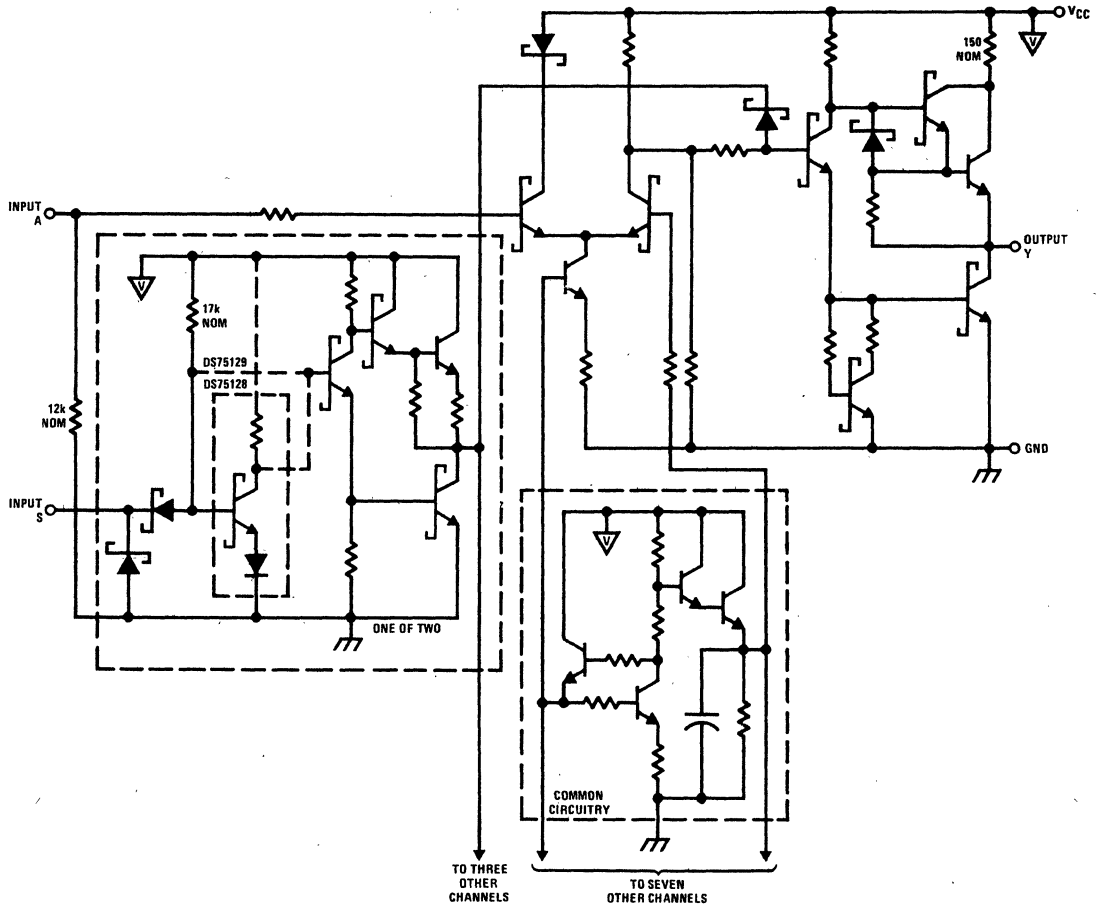
Note 2: For operation above 25°C free-air temperature, refer to Thermal Ratings for ICs, Section 12, Interface Databook.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

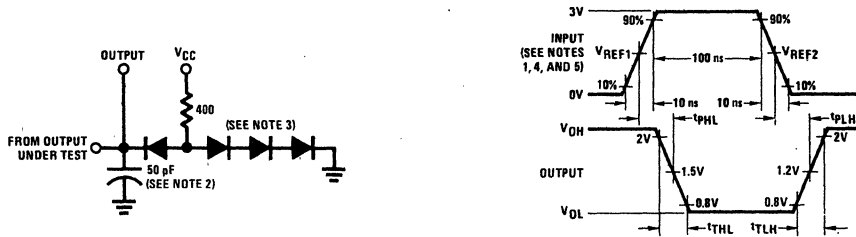
Note 4: Only one output should be shorted at a time.

Note 5: All typical values are at $V_{CC} = 5V, T_A = 25^\circ C$.

Schematic Diagram (each receiver)



AC Test Circuit and Switching Time Waveforms

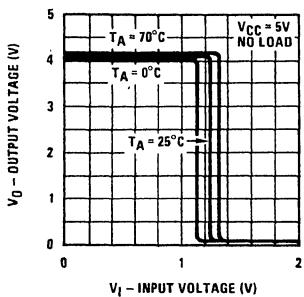


- Note 1:** Input pulses are supplied by a generator having the following characteristics: $Z_O = 50\Omega$, PRR = 5 MHz.
- Note 2:** Includes probe and jig capacitance.
- Note 3:** All diodes are 1N3064 or equivalent.
- Note 4:** The strobe inputs of DS75129 are in-phase with the output.
- Note 5:** $V_{REF1} = 0.7V$ and $V_{REF2} = 1.7V$ for testing data (A) inputs, $V_{REF1} = V_{REF2} = 1.3V$ for strobe inputs.

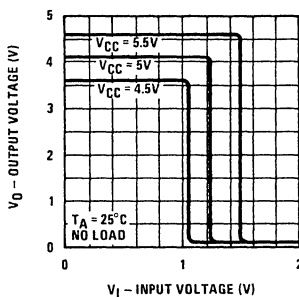
FIGURE 1

Typical Characteristics

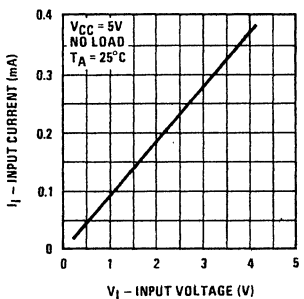
Voltage Transfer Characteristics From A Inputs



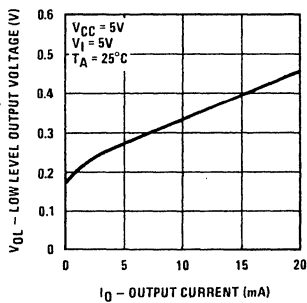
Voltage Transfer Characteristics From A Inputs



Input Current vs Input Voltage, A Inputs



Low-Level Output Voltage vs Output Current



DS75150 Dual Line Driver

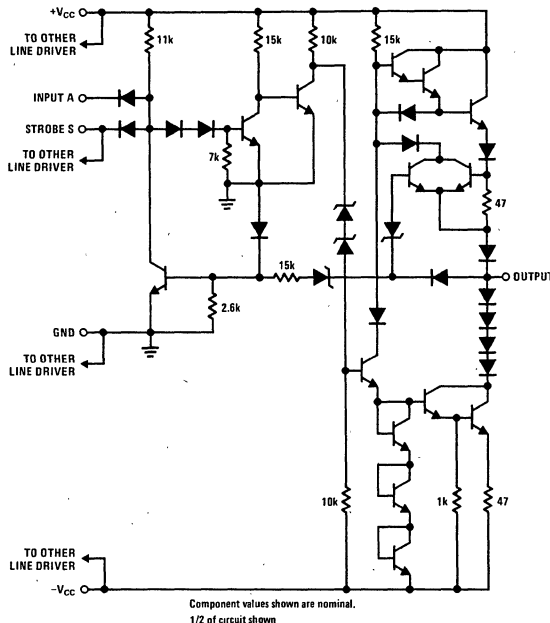
General Description

The DS75150 is a dual monolithic line driver designed to satisfy the requirements of the standard interface between data terminal equipment and data communication equipment as defined by EIA Standard RS-232-C. A rate of 20,000 bits per second can be transmitted with a full 2500 pF load. Other applications are in data-transmission systems using relatively short single lines, in level translators, and for driving MOS devices. The logic input is compatible with most TTL and LS families. Operation is from -12V and $+12\text{V}$ power supplies.

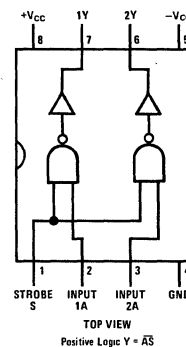
Features

- Withstands sustained output short-circuit to any low impedance voltage between -25V and $+25\text{V}$
- $2\mu\text{s}$ max transition time through the -3V to $+3\text{V}$ transition region under full 2500 pF load
- Inputs compatible with most TTL and LS families
- Common strobe input
- Common inverting output
- Slew rate can be controlled with an external capacitor at the output
- Standard supply voltages $\pm 12\text{V}$

Schematic and Connection Diagrams



Dual-In-Line Package



Order Number DS75150J-8 or DS75150N
See NS Package J08A or N08A

Absolute Maximum Ratings (Note 1)

Supply Voltage +V _{CC}	15V
Supply Voltage -V _{CC}	-15V
Input Voltage	15V
Applied Output Voltage	±25V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1133 mW
Molded Package	1022 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 7.6 mW/°C above 25°C; derate molded package 8.2 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (+V _{CC})	10.8	13.2	V
Supply Voltage (-V _{CC})	-10.8	-13.2	V
Input Voltage (V _I)	0	+5.5	V
Output Voltage (V _O)		±15	V
Operating Ambient Temperature Range (T _A)	0	+70	°C

DC Electrical Characteristics (Notes 2, 3, 4 and 5)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH} High-Level Input Voltage	(Figure 1)	2			V	
V _{IL} Low-Level Input Voltage	(Figure 2)			0.8	V	
V _{OH} High-Level Output Voltage	+V _{CC} = 10.8V, -V _{CC} = -13.2V, V _{IL} = 0.8V, R _L = 3 kΩ to 7 kΩ, (Figure 2)	5	8		V	
V _{OL} Low-Level Output Voltage	+V _{CC} = 10.8V, -V _{CC} = -10.8V, V _{IH} = 2V, R _L = 3 kΩ to 7 kΩ, (Figure 1)		-8	-5	V	
I _{IH} High-Level Input Current	+V _{CC} = 13.2V, -V _{CC} = -13.2V, Data Input V _I = 2.4V, (Figure 3)		1	10	μA	
	+V _{CC} = 13.2V, -V _{CC} = -13.2V, Strobe Input V _I = 2.4V, (Figure 3)		2	20	μA	
I _{IL} Low-Level Input Current	+V _{CC} = 13.2V, -V _{CC} = -13.2V, Data Input V _I = 0.4V, (Figure 3)		-1	-1.6	mA	
	+V _{CC} = 13.2V, -V _{CC} = -13.2V, Strobe Input V _I = 0.4V, (Figure 3)		-2	-3.2	mA	
I _{OS} Short-Circuit Output Current	+V _{CC} = 13.2V, -V _{CC} = -13.2V, (Figure 4), Note 4	V _O = 25V		2	5	mA
		V _O = -25V		-3	-6	mA
		V _O = 0V, V _I = 3V		15	30	mA
		V _O = 0V, V _I = 0V		-15	-30	mA
+I _{CCH} Supply Current From +V _{CC} , High-Level Output	+V _{CC} = 13.2V, -V _{CC} = -13.2V, V _I = 0V, R _L = 3 kΩ, T _A = 25°C, (Figure 5)		10	22	mA	
-I _{CCH} Supply Current From -V _{CC} , High-Level Output	+V _{CC} = 13.2V, -V _{CC} = -13.2V, V _I = 0V, R _L = 3 kΩ, T _A = 25°C, (Figure 5)		-1	-10	mA	
+I _{CCL} Supply Current From +V _{CC} , Low-Level Output	+V _{CC} = 13.2V, -V _{CC} = -13.2V, V _I = 3V, R _L = 3 kΩ, T _A = 25°C, (Figure 5)		8	17	mA	
-I _{CCL} Supply Current From -V _{CC} , Low-Level Output	+V _{CC} = 13.2V, -V _{CC} = -13.2V, V _I = 3V, R _L = 3 kΩ, T _A = 25°C, (Figure 5)		-9	-20	mA	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS75150. All typical values are for T_A = 25°C and +V_{CC} = 12V, -V_{CC} = -12V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: The algebraic convention where the most-positive (least-negative) limit is designated as maximum is used in this data sheet for logic levels only, e.g., when -5V is the maximum, the typical value is a more-negative voltage.

AC Electrical Characteristics (+V_{CC} = 12V, -V_{CC} = -12V, T_A = 25°C)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{TLH}	Transition Time, Low-to-High Level Output C _L = 2500 pF, R _L = 3 kΩ to 7 kΩ, (Figure 6)	0.2	1.4	2	μs
t _{THL}	Transition Time, High-to-Low Level Output C _L = 2500 pF, R _L = 3 kΩ to 7 kΩ, (Figure 6)	0.2	1.5	2	μs
t _{TLH}	Transition Time, Low-to-High Level Output C _L = 15 pF, R _L = 7 kΩ, (Figure 6)		40		ns
t _{THL}	Transition Time, High-to-Low Level Output C _L = 15 pF, R _L = 7 kΩ, (Figure 6)		20		ns
t _{PLH}	Propagation Delay Time, Low-to-High Level Output C _L = 15 pF, R _L = 7 kΩ, (Figure 6)		60		ns
t _{PHL}	Propagation Delay Time, High-to-Low Level Output C _L = 15 pF, R _L = 7 kΩ, (Figure 6)		45		ns

DC Test Circuits

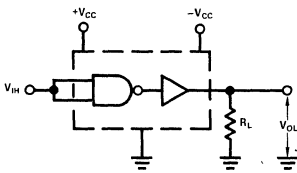


FIGURE 1. V_{IH}, V_{OL}

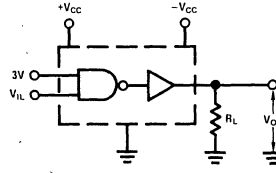
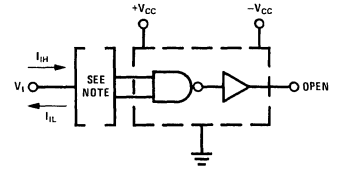
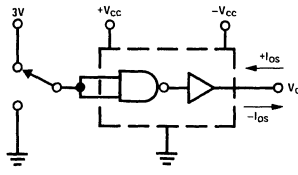


FIGURE 2. V_{IL}, V_{OH}



Note: When testing I_{iH}, the other input is at 3V; when testing I_{iL}, the other input is open.

FIGURE 3. I_{iH}, I_{iL}



I_{OS} is tested for both input conditions at each of the specified output conditions.

FIGURE 4. I_{OS}

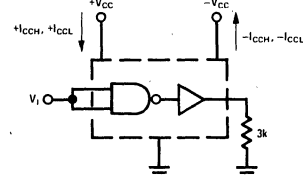
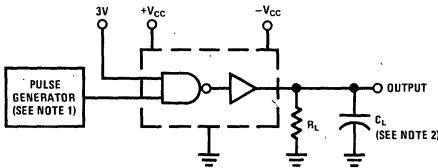


FIGURE 5. I_{CCH}+, I_{CCH}-, I_{CC+}+, I_{CC-}

AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: duty cycle ≤ 50%, Z_{OUT} ≈ 50Ω.
 Note 2: C_L includes probe and jig capacitance.

FIGURE 6.

Typical Performance Characteristics

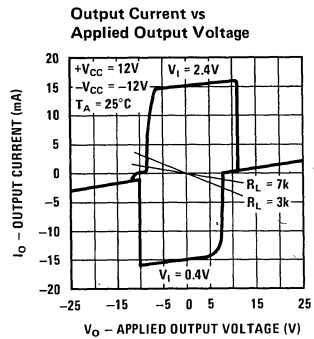


FIGURE 7.

DS75154 Quad Line Receiver

General Description

The DS75154 is a quad monolithic line receiver designed to satisfy the requirements of the standard interface between data terminal equipment and data communication equipment as defined by EIA Standard RS-232C. Other applications are in relatively short, single-line, point-to-point data transmission systems and for level translators. Operation is normally from a single 5V supply; however, a built-in option allows operation from a 12V supply without the use of additional components. The output is compatible with most TTL and LS circuits when either supply voltage is used.

In normal operation, the threshold-control terminals are connected to the V_{CC1} terminal, pin 15, even if power is being supplied via the alternate V_{CC2} terminal, pin 16. This provides a wide hysteresis loop which is the difference between the positive-going and negative-going threshold voltages. In this mode, if the input voltage goes to zero, the output voltage will remain at the low or high level as determined by the previous input.

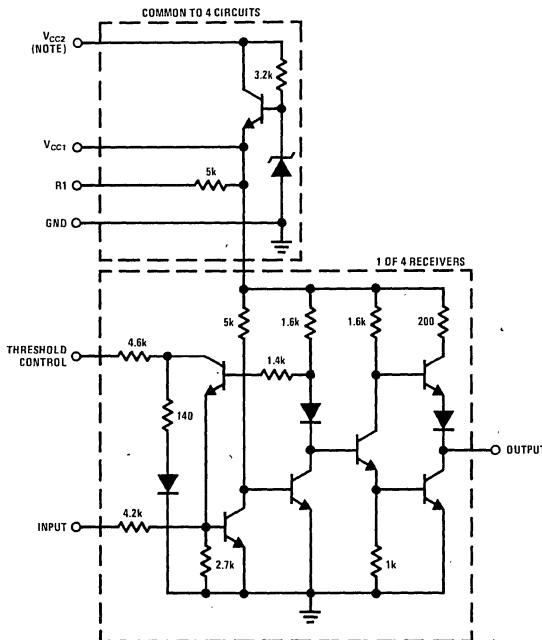
For fail-safe operation, the threshold-control terminals are open. This reduces the hysteresis loop by causing

the negative-going threshold voltage to be above zero. The positive-going threshold voltage remains above zero as it is unaffected by the disposition of the threshold terminals. In the fail-safe mode, if the input voltage goes to zero or an open-circuit condition, the output will go to the high level regardless of the previous input condition.

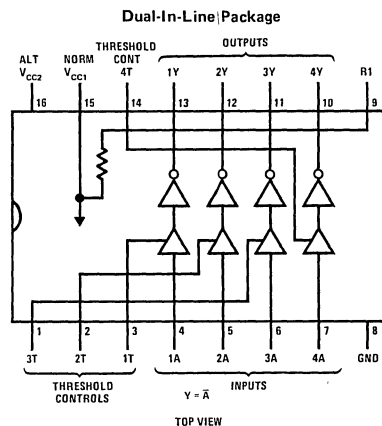
Features

- Input resistance, 3 k Ω to 7 k Ω over full RS-232C voltage range
- Input threshold adjustable to meet "fail-safe" requirements without using external components
- Inverting output compatible with TTL or LS
- Built-in hysteresis for increased noise immunity
- Output with active pull-up for symmetrical switching speeds
- Standard supply voltage—5V or 12V

Schematic and Connection Diagrams



Note: When using V_{CC1} (pin 15), V_{CC2} (pin 16) may be left open or shorted to V_{CC1} .
When using V_{CC2} , V_{CC1} must be left open or connected to the threshold control pins.



Order Number DS75154J or DS75154N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Normal Supply Voltage (Pin 15), (V _{CC1})	7V
Alternate Supply Voltage (Pin 16), (V _{CC2})	14V
Input Voltage	±25V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (Pin 15), (V _{CC1})	4.5	5.5	V
Alternate Supply Voltage (Pin 16) (V _{CC2})	10.8	13.2	V
Input Voltage		±15	V
Temperature, (T _A)	0	+70	°C

Electrical Characteristics (Notes 2, 3 and 4)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH} High-Level Input Voltage	(Figure 1)	3			V	
V _{IL} Low-Level Input Voltage	(Figure 1)			-3	V	
V _{T+} Positive-Going Threshold Voltage	(Figure 1)	Normal Operation	0.8	2.2	3	V
		Fail-Safe Operation	0.8	2.2	3	V
V _{T-} Negative-Going Threshold Voltage	(Figure 1)	Normal Operation	-3	-1.1	0	V
		Fail-Safe Operation	0.8	1.4	3	V
V _{T+} -V _{T-} Hysteresis	(Figure 1)	Normal Operation	0.8	3.3	6	V
		Fail-Safe Operation	0	0.8	2.2	V
V _{OH} High-Level Output Voltage	I _{OH} = -400μA, (Figure 1)	2.4	3.5		V	
V _{OL} Low-Level Output Voltage	I _{OL} = 16 mA, (Figure 1)		0.23	0.4	V	
r _i Input Resistance	(Figure 2)	ΔV _I = -25V to -14V	3	5	7	kΩ
		ΔV _I = -14V to -3V	3	5	7	kΩ
		ΔV _I = -3V to +3V	3	6		kΩ
		ΔV _I = 3V to 14V	3	5	7	kΩ
		ΔV _I = 14V to 25V	3	5	7	kΩ
V _{I(OPEN)} Open-Circuit Input Voltage	I _I = 0, (Figure 3)	0	0.2	2	V	
I _{OS} Short-Circuit Output Current (Note 5)	V _{CC1} = 5.5V, V _I = -5V, (Figure 4)	-10	-20	-40	mA	
I _{CC1} Supply Current From V _{CC1}	V _{CC1} = 5.5V, T _A = 25°C, (Figure 5)		20	35	mA	
I _{CC2} Supply Current From V _{CC2}	V _{CC2} = 13.2V, T _A = 25°C, (Figure 5)		23	40	mA	

Switching Characteristics (V_{CC1} = 5V, T_A = 25°C)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{PLH} Propagation Delay Time, Low-to-High Level Output	C _L = 50 pF, R _L = 390Ω, (Figure 6)		22		ns
t _{PHL} Propagation Delay Time, High-to-Low Level Output	C _L = 50 pF, R _L = 390Ω, (Figure 6)		20		ns
t _{TLH} Transition Time, Low-to-High Level Output	C _L = 50 pF, R _L = 390Ω (Figure 6)		9		ns
t _{THL} Transition Time, High-to-Low Level Output	C _L = 50 pF, R _L = 390Ω, (Figure 6)		6		ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

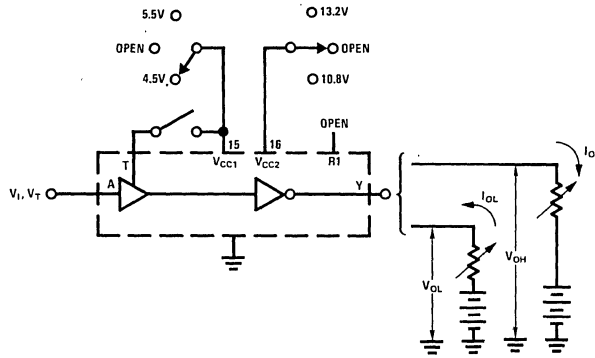
Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS75154. All typical values are for T_A = 25°C and V_{CC1} = 5V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: The algebraic convention where the most-positive (least-negative) limit is designated as maximum is used in this data sheet for logic and threshold levels only, e.g., when -3V is the maximum, the minimum limit is a more-negative voltage.

Note 5: Only one output at a time should be shorted.

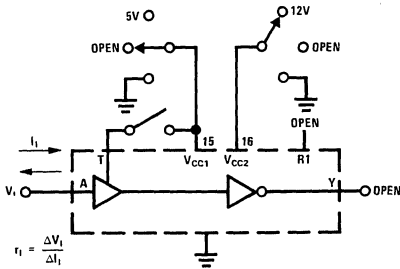
DC Test Circuits and Truth Tables



TEST	MEASURE	A	T	Y	V _{CC1} (PIN 15)	V _{CC2} (PIN 16)
Open-Circuit Input (fail-safe)	V _{OH}	Open	Open	I _{OH}	4.5V	Open
	V _{OH}	Open	Open	I _{OH}	Open	10.8V
V _{T+} min, V _{T-} (fail-safe)	V _{OH}	0.8V	Open	I _{OH}	5.5V	Open
	V _{OH}	0.8V	Open	I _{OH}	Open	13.2V
V _{T+} min (Normal)	V _{OH}	Note 1	Pin 15	I _{OH}	5.5V and T	Open
	V _{OH}	Note 1	Pin 15	I _{OH}	T	13.2V
V _{IL} max, V _{T-} min (Normal)	V _{OH}	-3V	Pin 15	I _{OH}	5.5V and T	Open
	V _{OH}	-3V	Pin 15	I _{OH}	T	13.2V
V _{IH} min, V _{T+} max, V _{T-} max (fail-safe)	V _{OL}	3V	Open	I _{OL}	4.5V	Open
	V _{OL}	3V	Open	I _{OL}	Open	10.8V
V _{IH} min, V _{T+} max (Normal)	V _{OL}	3V	Pin 15	I _{OL}	4.5V and T	Open
	V _{OL}	3V	Pin 15	I _{OL}	T	10.8V
V _{T-} max (Normal)	V _{OL}	Note 2	Pin 15	I _{OL}	5.5V and T	Open
	V _{OL}	Note 2	Pin 15	I _{OL}	T	13.2V

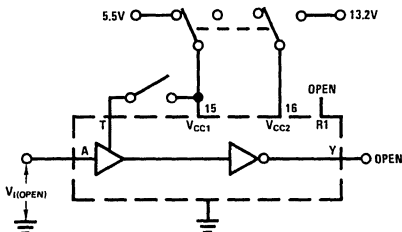
Note 1: Momentarily apply -5V, then 0.8V.
 Note 2: Momentarily apply 5V, then ground.

FIGURE 1. V_{IH}, V_{IL}, V_{T+}, V_{T-}, V_{OH}, V_{OL}



T	V _{CC1} (Pin 15)	V _{CC2} (Pin 16)
Open	5V	Open
Open	Gnd	Open
Open	Open	Open
Pin 15	T and 5V	Open
Gnd	Gnd	Open
Open	Open	12V
Open	Open	Gnd
Pin 15	T	12V
Pin 15	T	Gnd
Pin 15	T	Open

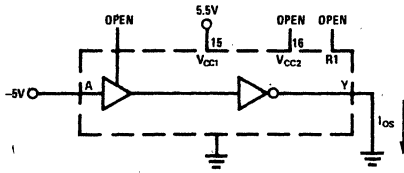
FIGURE 2. r_i



T	V _{CC1} (Pin 15)	V _{CC2} (Pin 16)
Open	5.5V	Open
Pin 15	5.5V	Open
Open	Open	13.2V
Pin 15	T	13.2V

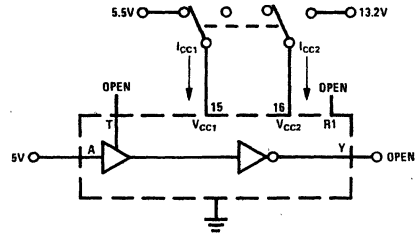
FIGURE 3. V₁(OPEN)

DC Test Circuits (Continued)



Each output is tested separately.

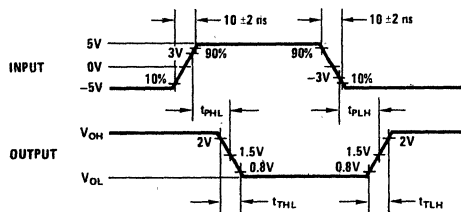
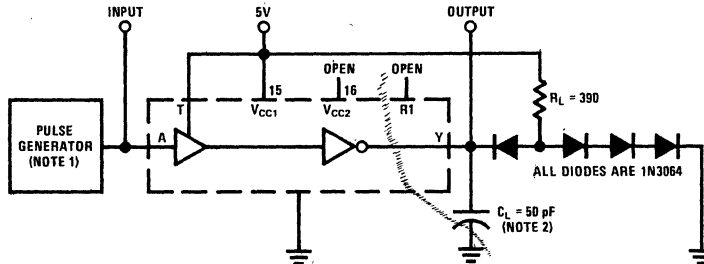
FIGURE 4. I_{OS}



All four line receivers are tested simultaneously.

FIGURE 5. I_{CC}

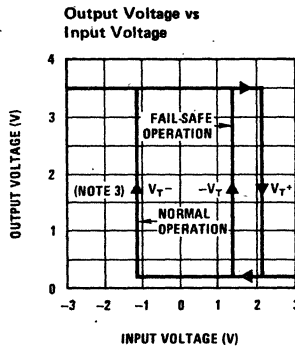
AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\Omega$, $t_W = 200$ ns, duty cycle $\leq 20\%$.
 Note 2: C_L includes probe and jig capacitance

FIGURE 6.

Typical Performance Characteristics



DS7820/DS8820 Dual Line Receiver

General Description

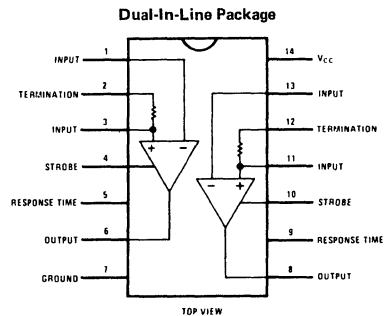
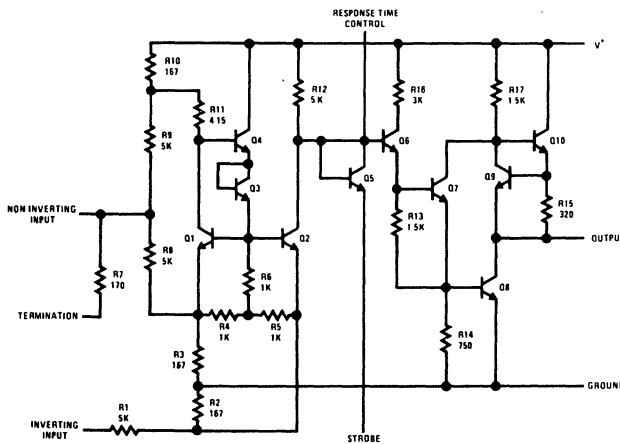
The DS7820, specified from -55°C to $+125^{\circ}\text{C}$, and the DS8820, specified from 0°C to $+70^{\circ}\text{C}$, are digital line receivers with two completely independent units fabricated on a single silicon chip. Intended for use with digital systems connected by twisted pair lines, they have a differential input designed to reject large common mode signals while responding to small differential signals. The output is directly compatible with TTL or LS integrated circuits.

Features

- Each channel can be strobed independently
- High input resistance
- Fan out of two with TTL integrated circuits

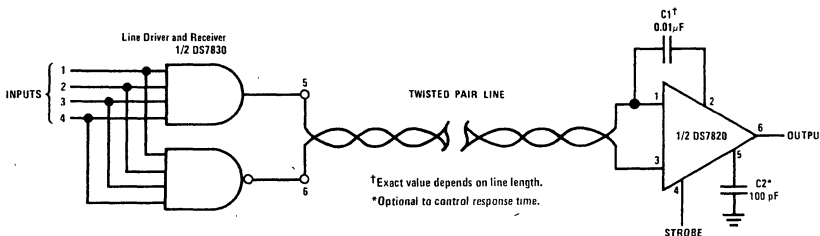
The response time can be controlled with an external capacitor to eliminate noise spikes, and the output state is determined for open inputs. Termination resistors for the twisted pair line are also included in the circuit. Both the DS7820 and the DS8820 are specified, worst case, over their full operating temperature range, for ± 10 -percent supply voltage variations and over the entire input voltage range.

Schematic and Connection Diagrams



Order Number DS7820J, DS8820J
or DS8820N
See NS Package J14A or N14A

Typical Application



[†]Exact value depends on line length.
^{*}Optional to control response time.

Absolute Maximum Ratings (Note 1)

Supply Voltage	8.0V
Input Voltage	±20V
Differential Input Voltage	±20V
Strobe Voltage	8.0V
Output Sink Current	25 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 sec)	300°C

*Derate cavity package 8.7 mW/°C above 25°C; derate molded package 9.7 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})			
DS7820	4.5	5.5	V
DS8820	4.75	5.25	V
Temperature (T_A)			
DS7820	-55	+125	°C
DS8820	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{TH} Input Threshold Voltage	$V_{CM} = 0$	-0.5	0	0.5	V
	$-15V \leq V_{CM} \leq 15V$	-1.0	0	1.0	V
V_{OH} High Output Level	$I_{OUT} \leq 0.2$ mA	2.5		5.5	V
V_{OL} Low Output Level	$I_{SINK} \leq 3.5$ mA	0		0.4	V
R_{I^-} Inverting Input Resistance		3.6	5.0		k Ω
R_{I^+} Non-Inverting Input Resistance		1.8	2.5		k Ω
R_T Line Termination Resistance	$T_A = 25^\circ\text{C}$	120	170	250	Ω
t_r Response Time	$C_{DELAY} = 0$		40		ns
	$C_{DELAY} = 100$ pF		150		ns
I_{ST} Strobe Current	$V_{STROBE} = 0.4V$		-1.0	-1.4	mA
	$V_{STROBE} = 5.5V$			5.0	μA
I_{CC} Power Supply Current	$V_{IN} = 15V$		3.2	6.0	mA
	$V_{IN} = 0$		5.8	10.2	mA
	$V_{IN} = -15V$		8.3	15.0	mA
I_{IN^+} Non-Inverting Input Current	$V_{IN} = 15V$		5.0	7.0	mA
	$V_{IN} = 0$	-1.6	-1.0		mA
	$V_{IN} = -15V$	-9.8	-7.0		mA
I_{IN^-} Inverting Input Current	$V_{IN} = 15V$		3.0	4.2	mA
	$V_{IN} = 0$		0	-0.5	mA
	$V_{IN} = -15V$	-4.2	-3.0		mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

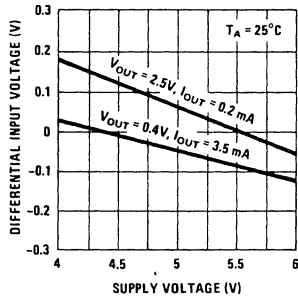
Note 2: These specifications apply for $4.5V \leq V_{CC} \leq 5.5V$, $-15V \leq V_{CM} \leq 15V$ and $-55^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$ for the DS7820 or $0^\circ\text{C} \leq T_A \leq +70^\circ\text{C}$ for the DS8820 unless otherwise specified; typical values given are for $V_{CC} = 5.0V$, $T_A = 25^\circ\text{C}$ and $V_{CM} = 0$ unless stated differently.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

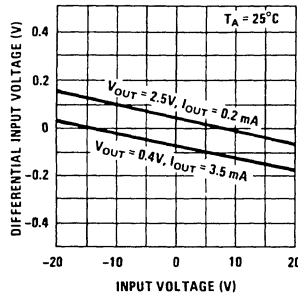
Note 4: The specifications and curves given are for one side only. Therefore, the total package dissipation and supply currents will be double the values given when both receivers are operated under identical conditions.

Typical Performance Characteristics (Note 3)

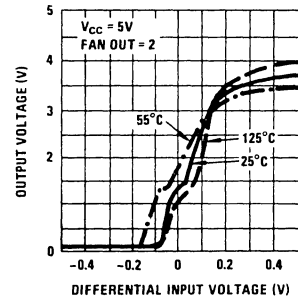
Supply Voltage Sensitivity



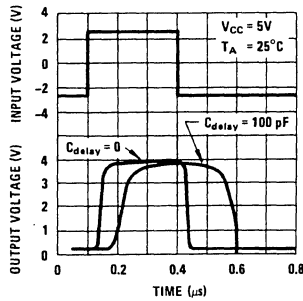
Common Mode Rejection



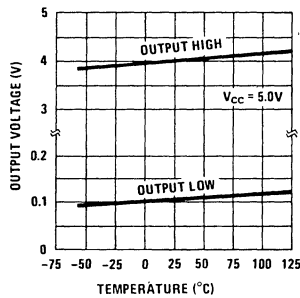
Transfer Function



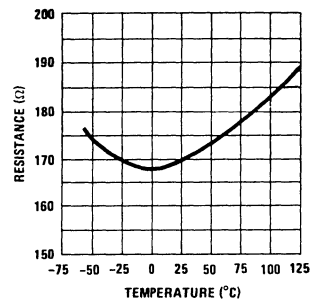
Response Time



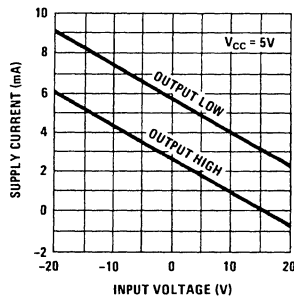
Output Voltage Levels



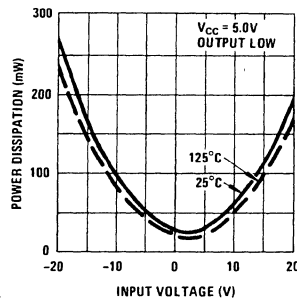
Termination Resistance



Positive Supply Current



Internal Power Dissipation



DS7820A/DS8820A Dual Line Receiver

General Description

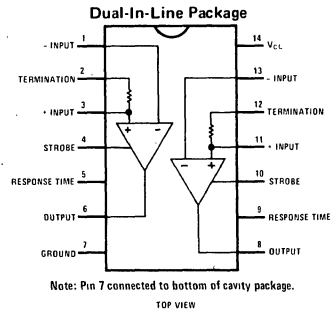
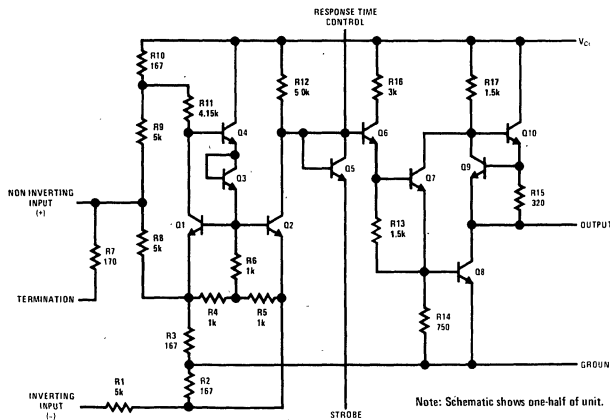
The DS7820A and the DS8820A are improved performance digital line receivers with two completely independent units fabricated on a single silicon chip. Intended for use with digital systems connected by twisted pair lines, they have a differential input designed to reject large common mode signals while responding to small differential signals. The output is directly compatible with TTL or LS integrated circuits. Some important design features include:

- Operation from a single +5V logic supply
- Input voltage range of $\pm 15V$
- Strobe low forces output to "1" state
- High input resistance

- Fanout of ten with TTL integrated circuits
- Outputs can be wire OR'ed
- Series 54/74 compatible

The response time can be controlled with an external capacitor to reject input noise spikes. The output state is a logic "1" for both inputs open. Termination resistors for the twisted pair line are also included in the circuit. Both the DS7820A and the DS8820A are specified, worst case, over their full operating temperature range ($-55^{\circ}C$ to $125^{\circ}C$ and $0^{\circ}C$ to $70^{\circ}C$ respectively), over the entire input voltage range, for $\pm 10\%$ supply voltage variations.

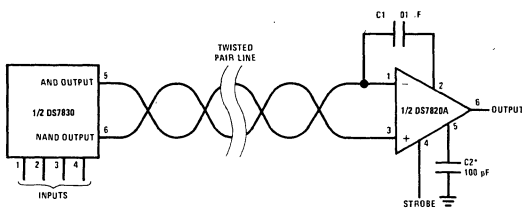
Schematic and Connection Diagrams



Order Number DS7820AJ, DS8820AJ or DS8820AN
See NS Package J14A or N14A

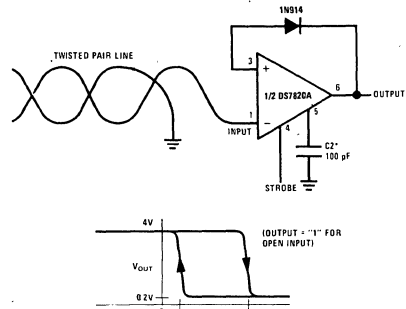
Typical Applications

Differential Line Driver and Receiver



*Optional to control response time.

Single Ended (EIA-RS232C) Receiver with Hysteresis



Absolute Maximum Ratings (Note 1)

Supply Voltage	8.0V
Common-Mode Voltage	±20V
Differential Input Voltage	±20V
Strobe Voltage	8.0V
Output Sink Current	50 mA
Storage Temperature Range	-65°C to 150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW
Lead Temperature (Soldering, 10 sec)	300°C

*Derate cavity package 8.7 mW/°C above 25°C; derate molded package 9.7 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7820A	4.5	5.5	V
DS8820A	4.75	5.25	V
Temperature (T _A)			
DS7820A	-55	+125	°C
DS8820A	0	+70	°C

Electrical Characteristics (Notes 2, 3, and 4)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{TH} Differential Threshold Voltage	I _{OUT} = -400μA, -3V ≤ V _{CM} ≤ +3V		0.06	0.5	V	
	V _{OUT} ≥ 2.5V, -15V ≤ V _{CM} ≤ +15V		0.06	1.0	V	
	I _{OUT} = +16 mA, -3V ≤ V _{CM} ≤ +3V		-0.08	-0.5	V	
	V _{OUT} ≤ 0.4V, -15V ≤ V _{CM} ≤ +15V		-0.08	-1.0	V	
R _I ⁻ Inverting Input Resistance	-15V ≤ V _{CM} ≤ +15V	3.6	5		kΩ	
R _I ⁺ Non-Inverting Input Resistance	-15V ≤ V _{CM} ≤ +15V	1.8	2.5		kΩ	
R _T Line Termination Resistance	T _A = 25°C	120	170	250	Ω	
I _I ⁻ Inverting Input Current	V _{CM} = 15V		3.0	4.2	mA	
	V _{CM} = 0V		0	-0.5	mA	
	V _{CM} = -15V		-3.0	-4.2	mA	
I _I ⁺ Non-Inverting Input Current	V _{CM} = 15V		5.0	7.0	mA	
	V _{CM} = 0V		-1.0	-1.6	mA	
	V _{CM} = -15V		-7.0	-9.8	mA	
I _{CC} Power Supply Current One Side Only	I _{OUT} = Logical "0"	V _{DIFF} = -1V, V _{CM} = 15V		3.9	6.0	mA
		V _{DIFF} = -1V, V _{CM} = -15V		9.2	14.0	mA
		V _{DIFF} = -0.5V, V _{CM} = 0V		6.5	10.2	mA
V _{OH} Logical "1" Output Voltage	I _{OUT} = -400μA, V _{DIFF} = 1V	2.5	4.0	5.5	V	
V _{OL} Logical "0" Output Voltage	I _{OUT} = +16 mA, V _{DIFF} = -1V	0	0.22	0.4	V	
V _{SH} Logical "1" Strobe Input Voltage	I _{OUT} = +16 mA, V _{OUT} ≤ 0.4V, V _{DIFF} = -3V	2.1			V	
V _{SL} Logical "0" Strobe Input Voltage	I _{OUT} = -400μA, V _{OUT} ≥ 2.5V, V _{DIFF} = -3V			0.9	V	
I _{SH} Logical "1" Strobe Input Current	V _{STROBE} = 5.5V, V _{DIFF} = 3V		0.01	5.0	μA	
I _{SL} Logical "0" Strobe Input Current	V _{STROBE} = 0.4V, V _{DIFF} = -3V		-1.0	-1.4	mA	
I _{SC} Output Short Circuit Current	I _{OUT} = 0V, V _{CC} = 5.5V, V _{STROBE} = 0V	-2.8	-4.5	-6.7	mA	

Switching Characteristics T_A = 25°C, V_{CC} = 5V, unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd0} Propagation Delay, Differential Input to "0" Output	R _L = 400Ω, C _L = 15 pF, see Figure 1		30	45	ns
t _{pd1} Propagation Delay, Differential Input to "1" Output			27	40	ns
t _{pd0} Propagation Delay, Strobe Input to "0" Output			16	25	ns
t _{pd1} Propagation Delay, Strobe Input to "1" Output			18	30	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

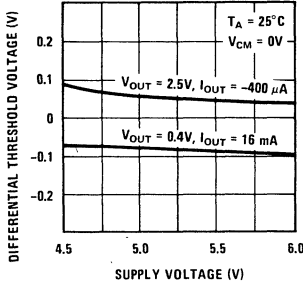
Note 2: These specifications apply for 4.5V ≤ V_{CC} ≤ 5.5V, -15V ≤ V_{CM} ≤ 15V and -55°C ≤ T_A ≤ +125°C for the DS7820A or 4.75V ≤ V_{CC} ≤ 5.25V, 0°C ≤ T_A ≤ +70°C for the DS8820A unless otherwise specified. Typical values given are for V_{CC} = 5.0V, T_A = 25°C and V_{CM} = 0V unless stated differently.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

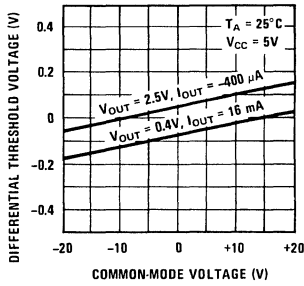
Note 4: Only one output at a time should be shorted.

Typical Performance Characteristics (Note 3)

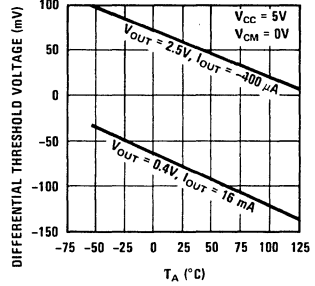
Supply Voltage Sensitivity



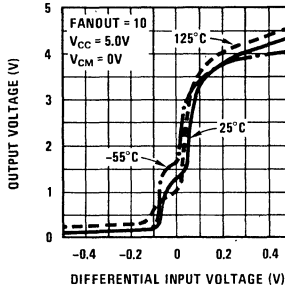
Common-Mode Voltage Sensitivity



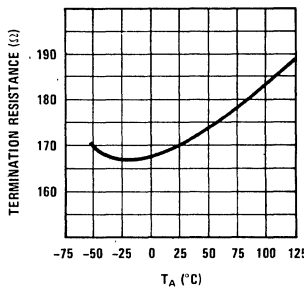
Temperature Sensitivity



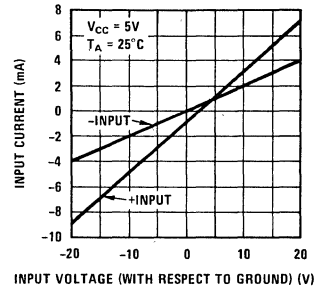
Transfer Function



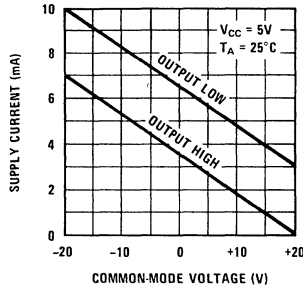
Termination Resistance



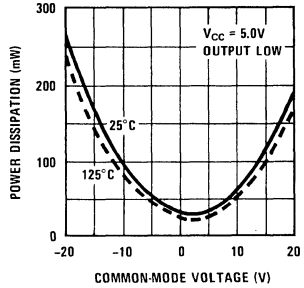
Input Characteristics



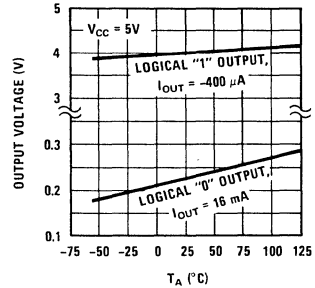
Power Supply Current



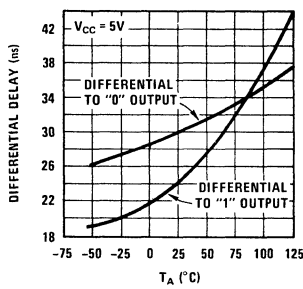
Internal Power Dissipation



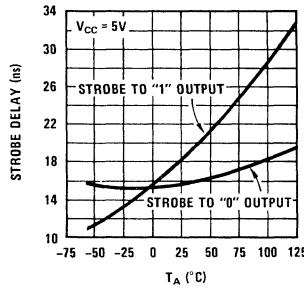
Output Voltage Levels



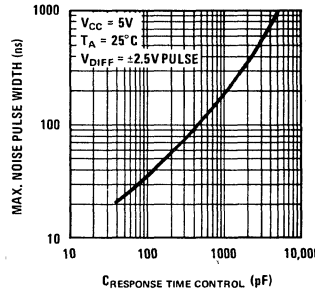
Differential Input Delays



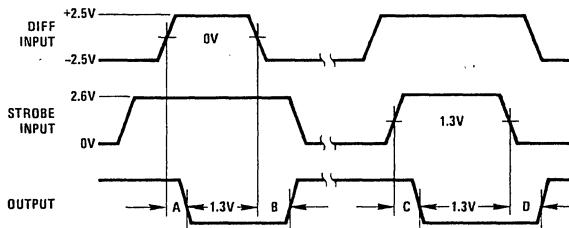
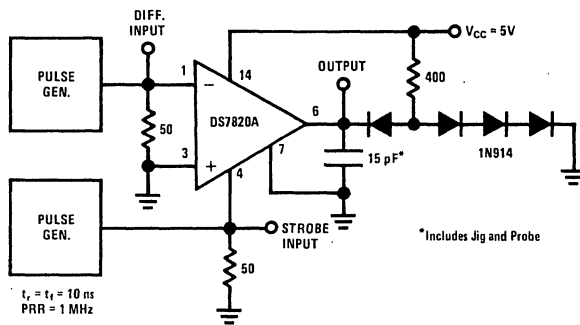
Strobe Delays



Noise Rejection



AC Test Circuit and Waveforms



- A = Differential Input to "0" Output
- B = Differential Input to "1" Output
- C = Strobe Input to "0" Output
- D = Strobe Input to "1" Output

FIGURE 1

DS78C20/DS88C20 Dual CMOS Compatible Differential Line Receiver

General Description

The DS78C20 and DS88C20 are high performance, dual differential, CMOS compatible line receivers for both balanced and unbalanced digital data transmission. The inputs are compatible with EIA and Federal Standards.

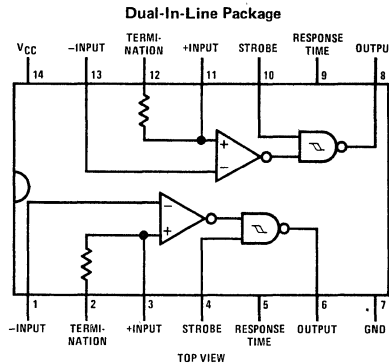
Input specifications meet or exceed those of the popular DS7820/DS8820 line receiver, and the pinout is identical.

A response pin is provided for controlling sensitivity to input noise spikes with an external capacitor. Each receiver includes a 180Ω terminating resistor, which may be used optionally on twisted pair lines. The DS78C20 is specified over a -55°C to +125°C operating temperature range, and the DS88C20 over a 0°C to +70°C range.

Features

- Meets requirements of EIA Standards RS-232-C RS-422 and RS-423, and Federal Standards 1020 and 1030
- Input voltage range of ±15V (differential or common-mode)
- Separate strobe input for each receiver
- 1/2 V_{CC} strobe threshold for CMOS compatibility
- 5k typical input impedance
- 50 mV input hysteresis
- 200 mV input threshold
- Operation voltage range = 4.5V to 15V
- DS7830/DS8830 or MM78C30/MM88C30 recommended driver

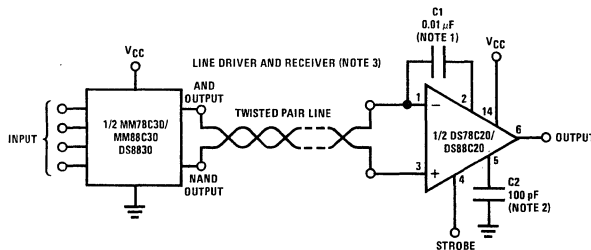
Connection Diagram



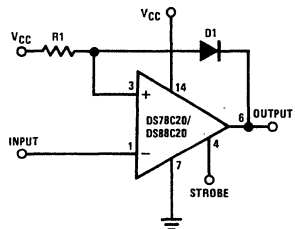
Order Number DS78C20J, DS88C20J or DS88C20N
See NS Package J14A or N14A

Typical Applications

RS-422/RS-423 Application



RS-232-C Application with Hysteresis

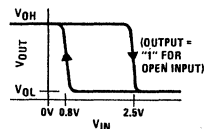


- Note 1:** (Optional internal termination resistor).
- a) Capacitor in series with internal line termination resistor, terminates the line and saves termination power. Exact value depends on line length.
 - b) Pin 1 connected to pin 2; terminates the line.
 - c) Pin 2 open; no internal line termination.
 - d) Transmission line may be terminated elsewhere or not at all.
- Note 2:** Optional to control response time.

Note 3: V_{CC} 4.5V to 15V for the DS78C20. For further information on line drivers and line receivers, refer to application notes AN-22, AN-83 and AN-108.

For signals which require fail-safe or have slow rise and fall times, use R1 and D1 as shown above. Otherwise, the positive input (pin 3 or 11) may be connected to ground.

V _{CC}	R1 ±5%
5V	4.3 kΩ
10V	15 kΩ
15V	24 kΩ



Absolute Maximum Ratings (Note 1)

Supply Voltage	18V
Common-Mode Voltage	±25V
Differential Input Voltage	±25V
Strobe Voltage	18V
Output Sink Current	50 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1364 mW
Molded Package	1280 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.1 mW/°C above 25°C; derate molded package 10.2 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	4.5	15	V
Temperature (T _A)			
DS78C20	-55	+125	°C
DS88C20	0	+70	°C
Common-Mode Voltage (V _{CM})	-15	+15	V

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
V _{TH}	Differential Threshold Voltage	I _{OUT} = -200 μA, V _{OUT} ≥ V _{CC} - 1.2V	-10V ≤ V _{CM} ≤ 10V		0.06	0.2	V
			-15V ≤ V _{CM} ≤ 15V		0.06	0.3	V
		I _{OUT} = 1.6 mA, V _{OUT} ≤ 0.5V	-10V ≤ V _{CM} ≤ 10V		-0.08	-0.2	V
			-15V ≤ V _{CM} ≤ 15V		-0.08	-0.3	V
R _{IN}	Input Resistance	-15V ≤ V _{CM} ≤ 15V			5		kΩ
R _T	Line Termination Resistance	T _A = 25°C		100	180	300	Ω
I _{IND}	Data Input Current (Unterminated)	V _{CM} = 10V			2	3.1	mA
		V _{CM} = 0V			0	-0.5	mA
		V _{CM} = -10V			-2	-3.1	mA
V _{THB}	Input Balance	I _{OUT} = 200 μA, V _{OUT} ≥ V _{CC} - 1.2V, R _S = 500Ω, (Note 5)	-7V ≤ V _{CM} ≤ 7V		0.1	0.4	V
		I _{OUT} = 1.6 mA, V _{OUT} ≤ 0.5V, R _S = 500Ω, (Note 5)	-7V ≤ V _{CM} ≤ 7V		-0.1	-0.4	V
V _{OH}	Logical "1" Output Voltage	I _{OUT} = -200 μA, V _{DIFF} = 1V		V _{CC} -1.2	V _{CC} -0.75		V
V _{OL}	Logical "0" Output Voltage	I _{OUT} = 1.6 mA, V _{DIFF} = -1V			0.25	0.5	V
I _{CC}	Power Supply Current	15V ≤ V _{CM} ≤ -15V, V _{DIFF} = -0.5V (Both Receivers)	V _{CC} = 5.5V		8	15	mA
			V _{CC} = 15V		15	30	mA
I _{IN(1)}	Logical "1" Strobe Input Current	V _{STROBE} = 15V, V _{DIFF} = 3V			15	100	μA
I _{IN(0)}	Logical "0" Strobe Input Current	V _{STROBE} = 0V, V _{DIFF} = -3V			-0.5	-100	μA
V _{IH}	Logical "1" Strobe Input Voltage	I _{OUT} = 1.6 mA, V _{OL} ≤ 0.5V	V _{CC} = 5V	3.5	2.5		V
			V _{CC} = 10V	8.0	5.0		V
			V _{CC} = 15V	12.5	7.5		V
V _{IL}	Logical "0" Strobe Input Voltage	I _{OUT} = -200 μA, V _{OH} = V _{CC} - 1.2V	V _{CC} = 5V		2.5	1.5	V
			V _{CC} = 10V		5.0	2.0	V
			V _{CC} = 15V		7.5	2.5	V
I _{OS}	Output Short-Circuit Current	V _{OUT} = 0V, V _{CC} = 15V, V _{STROBE} = 0V, (Note 4)		-5	-20	-40	mA

Switching Characteristics V_{CC} = 5V, T_A = 25°C

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd0(D)}	Differential Input to "0" Output		60	100	ns
t _{pd1(D)}	Differential Input to "1" Output		100	150	ns
t _{pd0(S)}	Strobe Input to "0" Output		30	70	ns
t _{pd1(S)}	Strobe Input to "1" Output		100	150	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

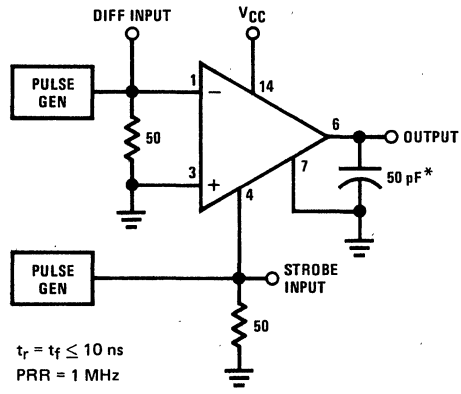
Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS78C20 and across the 0°C to +70°C range for the DS88C20. All typical values are for T_A = 25°C, V_{CC} = 5V and V_{CM} = 0V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

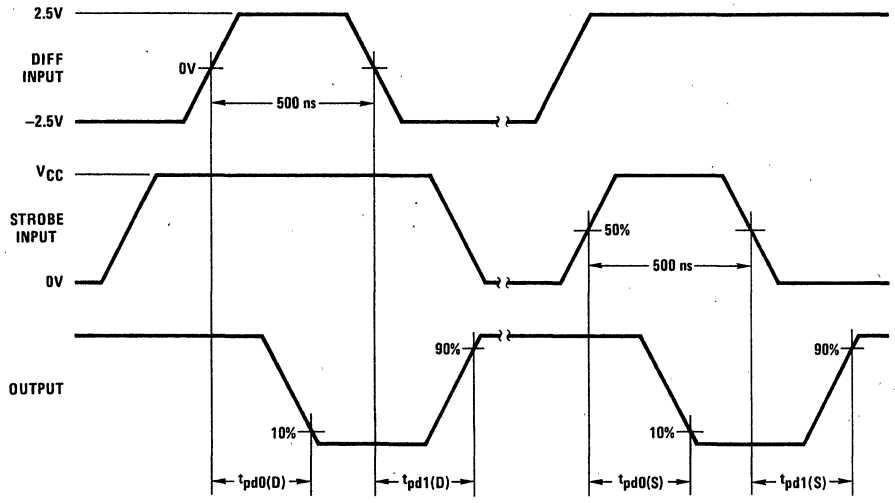
Note 4: Only one output at a time should be shorted.

Note 5: Refer to EIA-RS-422 for exact conditions.

AC Test Circuit and Switching Time Waveforms



*Includes probe and jig capacitance



DS7830/DS8830 Dual Differential Line Driver

General Description

The DS7830/DS8830 is a dual differential line driver that also performs the dual four-input NAND or dual four-input AND function.

TTL (Transistor-Transistor-Logic) multiple emitter inputs allow this line driver to interface with standard TTL systems. The differential outputs are balanced and are designed to drive long lengths of coaxial cable, strip line, or twisted pair transmission lines with characteristic impedances of 50Ω to 500Ω . The differential feature of the output eliminates troublesome ground-loop errors

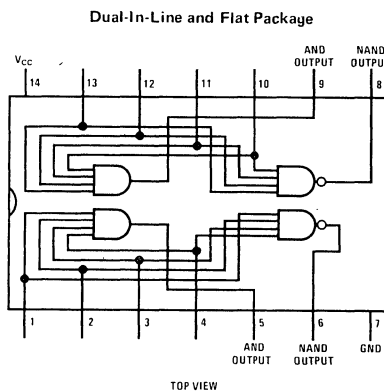
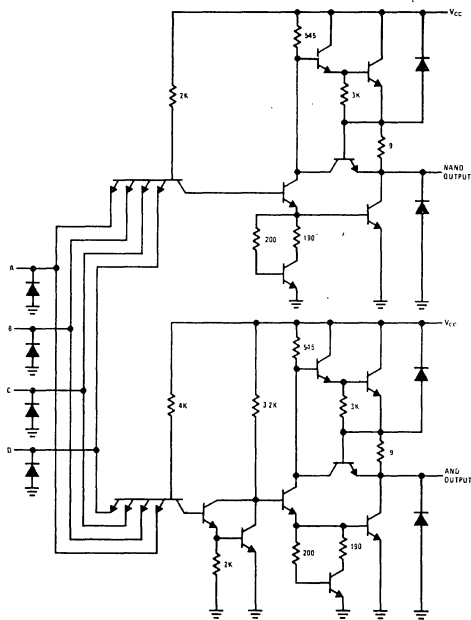
normally associated with single-wire transmissions.

Features

- Single 5 volt power supply
- Diode protected outputs for termination of positive and negative voltage transients
- Diode protected inputs to prevent line ringing
- High speed
- Short circuit protection

1

Schematic* and Connection Diagrams

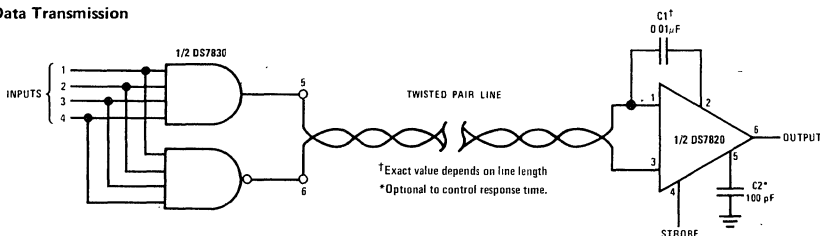


Order Number DS7830J,
DS8830J or DS8830N
See NS Package J14A or N14A

*2 PER PACKAGE.

Typical Application

Digital Data Transmission



Absolute Maximum Ratings (Note 1)

V _{CC}	7.0V
Input Voltage	5.5V
Storage Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 sec)	300°C
Output Short Circuit Duration (125°C)	1 second
Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW

*Derate cavity package 8.7 mW/°C above 25°C; derate molded package 9.7 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7830	4.5	5.5	V
DS8830	4.75	5.25	V
Temperature (T _A)			
DS7830	-55	+125	°C
DS8830	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH}	Logical "1" Input Voltage	2.0			V	
V _{IL}	Logical "0" Input Voltage			0.8	V	
V _{OH}	Logical "1" Output Voltage	V _{IN} = 0.8V	I _{OUT} = -0.8 mA	2.4		V
			I _{OUT} = 40 mA	1.8	3.3	V
V _{OL}	Logical "0" Output Voltage	V _{IN} = 2.0V	I _{OUT} = 32 mA		0.2	V
			I _{OUT} = 40 mA		0.22	0.5
I _{IH}	Logical "1" Input Current	V _{IN} = 2.4V			120	μA
		V _{IN} = 5.5V			2	mA
I _{IL}	Logical "0" Input Current	V _{IN} = 0.4V			-4.8	mA
I _{SC}	Output Short Circuit Current	V _{CC} = 5.0V, T _A = 125°C, (Note 4)	-40	-100	-120	mA
I _{CC}	Supply Current	V _{IN} = 5.0V, (Each Driver)		11	18	mA
V _I	Input Clamp	V _{CC} = Min; I _{IN} = -12 mA		-1.0	-1.5	V

Switching Characteristics T_A = 25°C, V_{CC} = 5V, unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd1}	Propagation Delay AND Gate R _L = 400Ω, C _L = 15 pF (Figure 1)		8	12	ns
t _{pd0}			11	18	ns
t _{pd1}	Propagation Delay NAND Gate R _L = 400Ω, C _L = 15 pF (Figure 1)		8	12	ns
t _{pd0}			5	8	ns
t ₁	Differential Delay Load, 100Ω and 5000 pF, (Figure 2)		12	16	ns
t ₂	Differential Delay Load, 100Ω and 5000 pF, (Figure 2)		12	16	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7830 and across the 0°C to +70°C range for the DS8830. Typical values are for T_A = 25°C and V_{CC} = 5.0V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

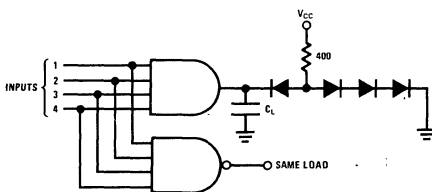


FIGURE 1.

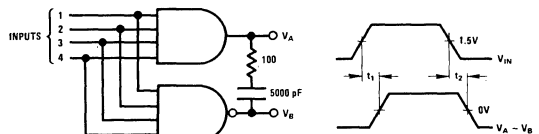
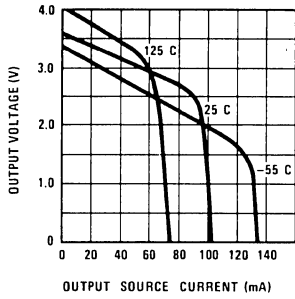


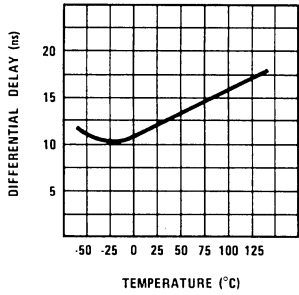
FIGURE 2.

Typical Performance Characteristics

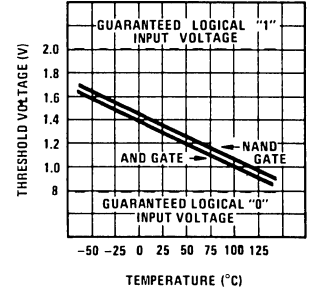
Output High Voltage (Logical "1") Vs Output Current



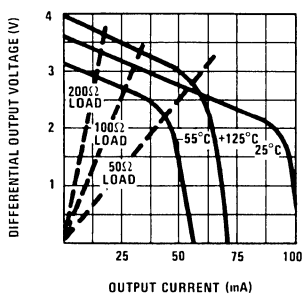
Differential Delay Vs Temperature



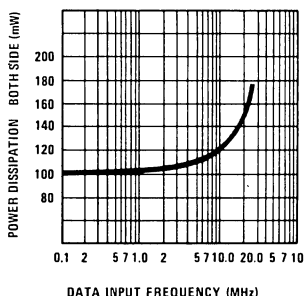
Threshold Voltage Vs Temperature



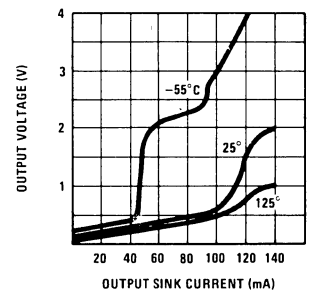
Differential Output Voltage (|V_{AND} - V_{NAND}|) Vs Differential Output Current



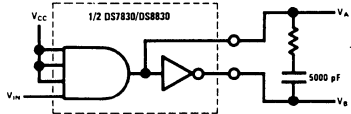
Power Dissipation (No Load) Vs Data Input Frequency



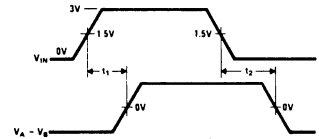
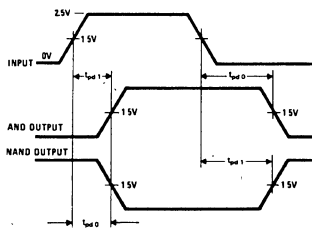
Output Low Voltage (Logical "0") Vs Output Current



AC Test Circuit



Switching Time Waveforms



f = 1 MHz
 t_r = t_f ≤ 10 ns (10% to 90%)
 Duty cycle = 50%

**DS7831/DS8831, DS7832/DS8832
Dual TRI-STATE® Line Driver**

General Description

Through simple logic control, the DS7831/DS8831, DS7832/DS8832 can be used as either a quad single-ended line driver or a dual differential line driver. They are specifically designed for party line (bus-organized) systems. The DS7832/DS8832 does not have the V_{CC} clamp diodes found on the DS7831/DS8831.

The DS7831 and DS7832 are specified for operation over the -55°C to +125°C military temperature range. The DS8831 and DS8832 are specified for operation over the 0°C to +70°C temperature range.

Features

- Series 54/74 compatible
- 17 ns propagation delay
- Very low output impedance—high drive capability
- 40 mA sink and source currents
- Gating control to allow either single-ended or differential operation
- High impedance output state which allows many outputs to be connected to a common bus line.

Mode of Operation

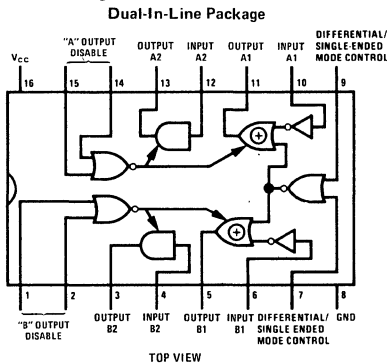
To operate as a quad single-ended line driver apply logical "0"s to the Output Disable pins (to keep the outputs in the normal low impedance mode) and apply logical "0"s to both Differential/Single-ended Mode Control inputs. All four channels will then operate independently and no signal inversion will occur between inputs and outputs.

To operate as a dual differential line driver apply logical "0"s to the Output Disable pins and apply at least one logical "1" to the Differential/Single-ended Mode Control inputs. The inputs to the A channels should be connected together and the inputs to the B channels should be connected together.

In this mode the signals applied to the resulting inputs will pass non-inverted on the A₂ and B₂ outputs and inverted on the A₁ and B₁ outputs.

When operating in a bus-organized system with outputs tied directly to outputs of other (continued)

Connection and Logic Diagram



**Order Number DS7831J, DS8831J,
DS7832J, DS8832J, DS8831N or DS8832N
See NS Package J16A or N16A**

Truth Table (Shown for A Channels Only)

"A" OUTPUT DISABLE	DIFFERENTIAL/SINGLE-ENDED MODE CONTROL	INPUT A1	OUTPUT A1	INPUT A2	OUTPUT A2
0 0	0 0	Logical "1" or Logical "0"	Same as Input A1	Logical "1" or Logical "0"	Same as Input A2
0 0	X 1 1 X	Logical "1" or Logical "0"	Opposite of Input A1	Logical "1" or Logical "0"	Same as Input A2
1 X X 1	X X	X	High impedance state	X	High impedance state

X = Don't Care

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Time that 2 bus-connected devices may be in opposite low impedance states simultaneously	∞
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 sec.)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7831, DS7832	4.5	5.5	V
DS8831, DS8832	4.75	5.25	V
Temperature (T _A)			
DS7831, DS7832	-55	+125	°C
DS8831, DS8832	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS		
V _{IH}	Logical "1" Input Voltage	V _{CC} = Min	2.0			V		
V _{IL}	Logical "0" Input Voltage	V _{CC} = Min			0.8	V		
V _{OH}	Logical "1" Output Voltage	DS7831, DS7832	V _{CC} = Min	I _O = -40 mA	1.8	2.3	V	
				I _O = -2 mA	2.4	2.7	V	
		DS8831, DS8832		I _O = -40 mA	1.8	2.5	V	
				I _O = -5.2 mA	2.4	2.9	V	
V _{OL}	Logical "0" Output Voltage	DS7831, DS7832	V _{CC} = Min	I _O = 40 mA		0.29	0.50	V
				I _O = 32 mA			0.40	V
		DS8831, DS8832		I _O = 40 mA		0.29	0.50	V
				I _O = 32 mA			0.40	V
I _{IH}	Logical "1" Input Current	V _{CC} = Max	DS7831, DS7832, V _{IN} = 5.5V			1	mA	
			DS8831, DS8832, V _{IN} = 2.4V			40	μA	
I _{IL}	Logical "0" Input Current	V _{CC} = Max, V _{IN} = 0.4V		-1.0	-1.6	mA		
I _{OD}	Output Disable Current	V _{CC} = Max, V _O = 2.4V or 0.4V	-40		40	μA		
I _{SC}	Output Short Circuit Current	V _{CC} = Max, (Note 4)	-40	-100	-120	mA		
I _{CC}	Supply Current	V _{CC} = Max in TRI-STATE		65	90	mA		
V _{CL1}	Input Diode Clamp Voltage	V _{CC} = 5.0V, T _A = 25°C, I _{IN} = -12 mA			-1.5	V		
V _{CL0}	Output Diode Clamp Voltage	V _{CC} = 5.0V, T _A = 25°C	I _{OUT} = -12 mA	DS7831/DS8831 DS7832/DS8832		-1.5	V	
			I _{OUT} = 12 mA	DS7831/DS8831		V _{CC} +1.5	V	

Switching Characteristics T_A = 25°C, V_{CC} = 5V, unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{p0}	Propagation Delay to a Logical "0" from Inputs A1, A2, B1, B2 Differential Single-ended Mode Control to Outputs		13	25	ns
t _{p1}	Propagation Delay to a Logical "1" from Inputs A1, A2, B1, B2 Differential Single-ended Mode Control to Outputs		13	25	ns
t _{1H}	Delay from Disable Inputs to High Impedance State (from Logical "1" Level)		6	12	ns
t _{0H}	Delay from Disable Inputs to High Impedance State (from Logical "0" Level)		14	22	ns
t _{H1}	Propagation Delay from Disable Inputs to Logical "1" Level (from High Impedance State)		14	22	ns
t _{H0}	Propagation Delay from Disable Inputs to Logical "0" Level (from High Impedance State)		18	27	ns

R_L = 400Ω, C_L = 15 pF
See Figures 4 and 5.

Notes

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to $+125^{\circ}\text{C}$ temperature range for the DS7831 and DS7832 and across the 0°C to $+70^{\circ}\text{C}$ range for the DS8831 and DS8832. All typical values are for $T_A = 25^{\circ}\text{C}$ and $V_{CC} = 5\text{V}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Applies for $T_A = 125^{\circ}\text{C}$ only. Only one output should be shorted at a time.

Mode of Operation (Continued)

DS7831/DS8831's, DS7832/DS8832's (Figure 1), all devices except one must be placed in the "high impedance" state. This is accomplished by ensuring that a logical "1" is applied to at least one of the Output Disable pins of each device which is to be in the "high impedance" state. A NOR gate was purposely chosen for this function since it is possible with only two DM5442/DM7442, BCD-to-decimal decoders, to decode as many as 100 DS7831/DS8831's, DS7832/DS8832's (Figure 2).

The unique device whose Disable inputs receive two logical "0" levels assumes the normal low

impedance output state, providing good capacitive drive capability and waveform integrity especially during the transition from the logical "0" to logical "1" state. The other outputs—in the high impedance state—take only a small amount of leakage current from the low impedance outputs. Since the logical "1" output current from the selected device is 100 times that of a conventional Series 54/74 device (40 mA vs. $400\ \mu\text{A}$), the output is easily able to supply that leakage current for several hundred other DS7831/DS8831's, DS7832/DS8832's and still have available drive for the bus line (Figure 3).

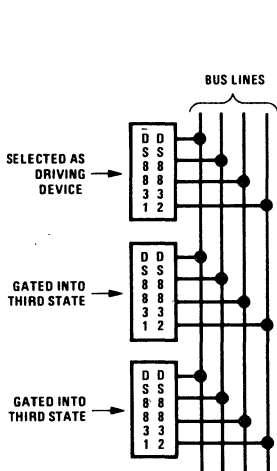


Figure 1

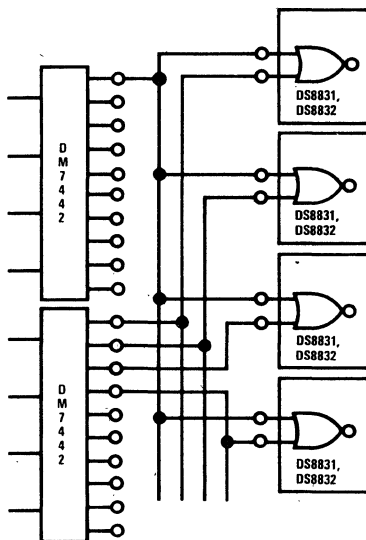


Figure 2

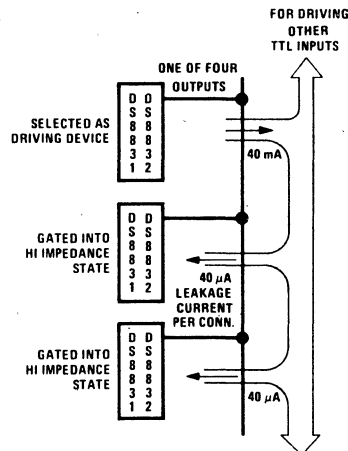
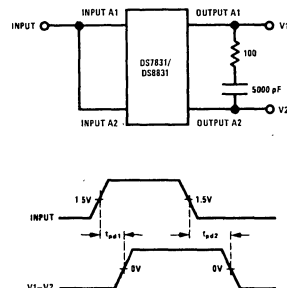
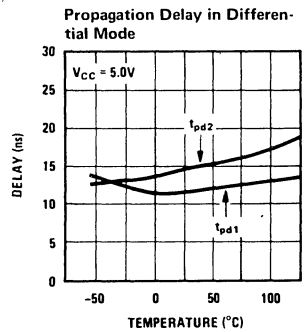
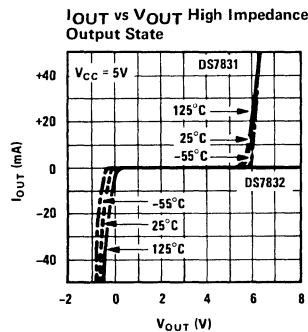
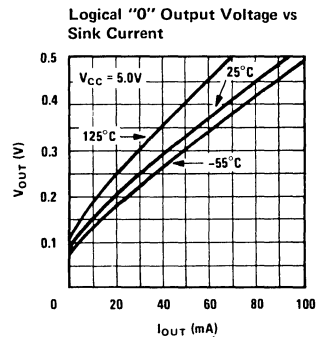
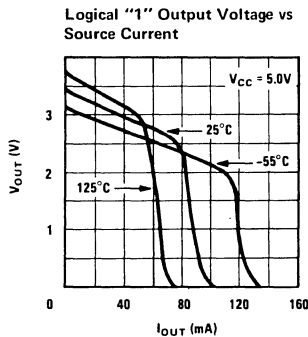
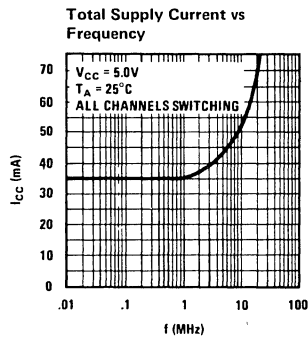
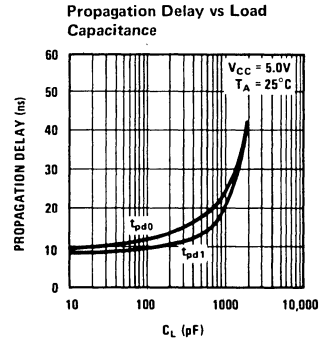
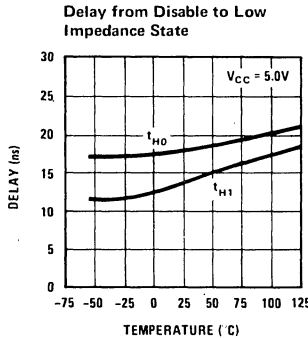
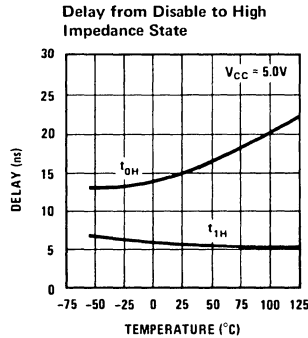
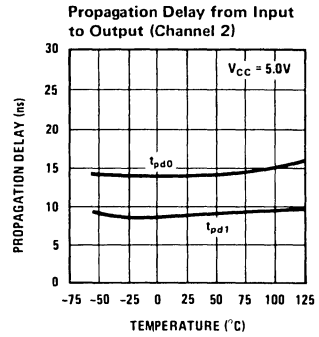
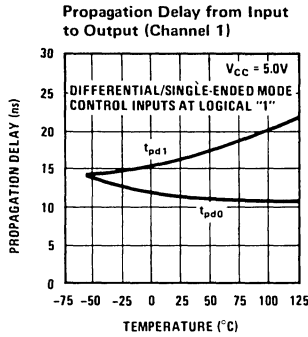
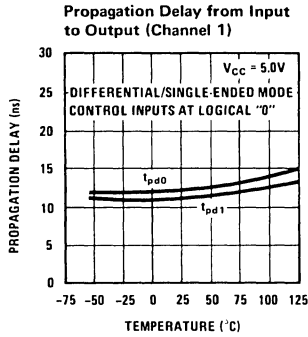
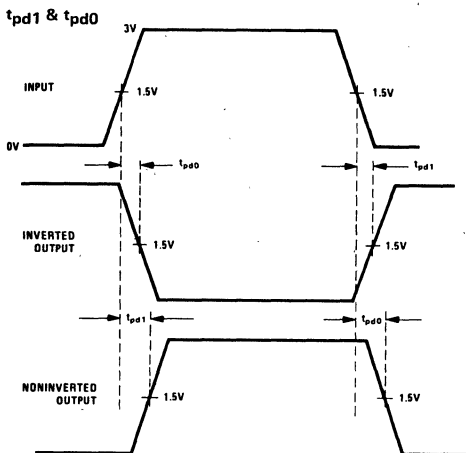


Figure 3

Typical Performance Characteristics



Switching Time Waveforms



Input characteristic:
 Amplitude = 3.0V
 Frequency = 1.0 MHz, 50% duty cycle
 $t_r = t_f \leq 10$ ns (10% to 90%)

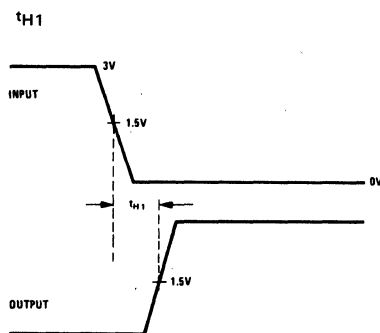
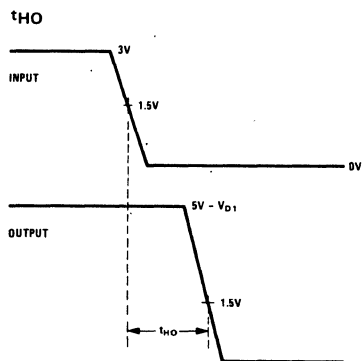
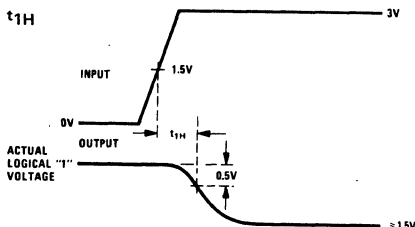
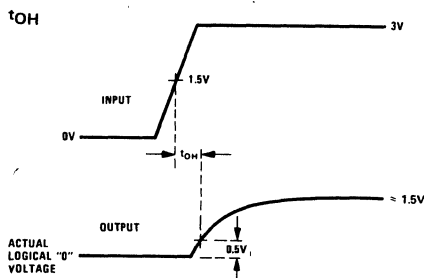
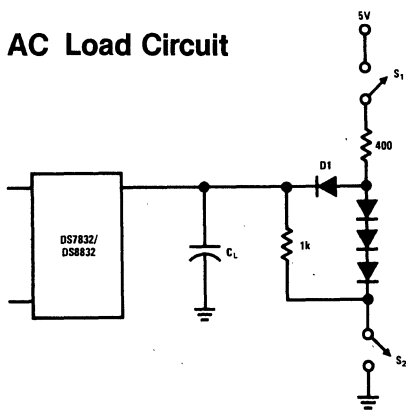


FIGURE 4

AC Load Circuit



	Switch S1	Switch S2	C_L
t_{pd1}	closed	closed	50 pF
t_{pd0}	closed	closed	50 pF
t_{OH}	closed	closed	* 5 pF
t_{LH}	closed	closed	* 5 pF
t_{HO}	closed	open	50 pF
t_{HL}	open	closed	50 pF

* Jig capacitance.

FIGURE 5

DS78C120/DS88C120 Dual CMOS Compatible Differential Line Receiver

General Description

The DS78C120 and DS88C120 are high performance, dual differential, CMOS compatible line receivers for both balanced and unbalanced digital data transmission. The inputs are compatible with EIA, Federal and MIL standards.

Input specifications meet or exceed those of the popular DS7820/DS8820 line receiver.

Features

- Full compatibility with EIA Standards RS232-C, RS422 and RS423, Federal Standards 1020, 1030 and MIL-188-114
- Input voltage range of $\pm 15\text{V}$ (differential or common-mode)
- Separate strobe input for each receiver
- $1/2 V_{CC}$ strobe threshold for CMOS compatibility
- 5k typical input impedance

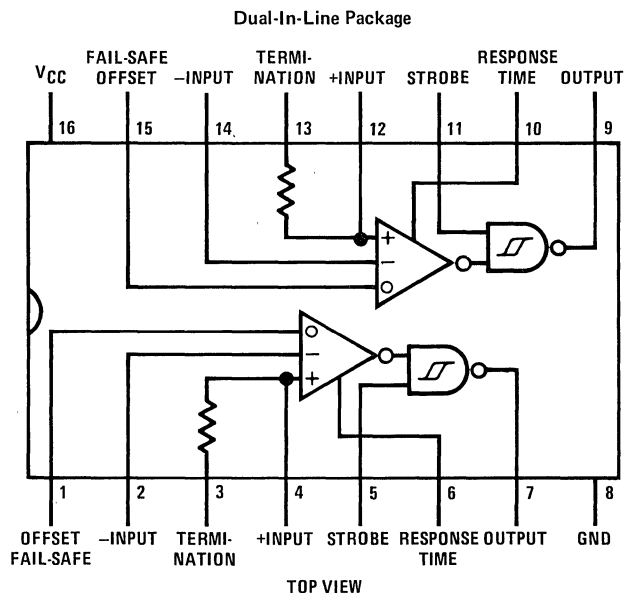
- 50 mV input hysteresis
- 200 mV input threshold
- Operation voltage range = 4.5V to 15V
- Separate fail-safe mode

Functional Description

The line receiver will discriminate a $\pm 200\text{ mV}$ input signal over a common-mode range of $\pm 10\text{V}$ and a $\pm 300\text{ mV}$ signal over a range of $\pm 15\text{V}$.

Circuit features include hysteresis and response control for applications where controlled rise and fall times and/or high frequency noise rejection are desirable. Threshold offset control is provided for fail-safe detection, should the input be open or short. Each receiver includes a 180Ω terminating resistor and the output gate contains a logic strobe for time discrimination. The DS78C120 is specified over a -55°C to $+125^\circ\text{C}$ temperature range and the DS88C120 from 0°C to $+70^\circ\text{C}$.

Connection Diagram



Order Number DS78C120J, DS88C120J
or DS88C120N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	18V
Input Voltage	±25V
Strobe Voltage	18V
Output Sink Current	50 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	4.5	15	V
Temperature (T _A)			
DS78C120	-55	+125	°C
DS88C120	0	+70	°C
Common-Mode Voltage (V _{CM})	-15	+15	V

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{TH} Differential Threshold Voltage	I _{OUT} = -200 μA, V _{OUT} ≥ V _{CC} - 1.2V	-7V ≤ V _{CM} ≤ 7V	0.06	0.2	V
		-15V ≤ V _{CM} ≤ 15V	0.06	0.3	V
V _{TL} Differential Threshold Voltage	I _{OUT} = 1.6 mA, V _{OUT} ≤ 0.5V	-7V ≤ V _{CM} ≤ 7V	-0.08	-0.2	V
		-15V ≤ V _{CM} ≤ 15V	-0.08	-0.3	V
V _{TH} Differential Threshold Voltage	I _{OUT} = -200 μA, V _{OUT} ≥ V _{CC} - 1.2V	-7V ≤ V _{CM} ≤ 7V	0.47	0.7	V
		-15V ≤ V _{CM} ≤ 15V	0.47	0.7	V
V _{TL} Fail-Safe Offset = 5V	I _{OUT} = 1.6 mA, V _{OUT} ≤ 0.5V	-7V ≤ V _{CM} ≤ 7V	0.2	0.42	V
R _{IN} Input Resistance	-15V ≤ V _{CM} ≤ 15V, 0V ≤ V _{CC} ≤ 15V	4	5		kΩ
R _T Line Termination Resistance	T _A = 25°C	100	180	300	Ω
R _O Offset Control Resistance	T _A = 25°C		56		kΩ
I _{IND} Data Input Current (Unterminated)	0V ≤ V _{CC} ≤ 15V	V _{CM} = 10V	2	3.1	mA
		V _{CM} = 0V	0	-0.5	mA
		V _{CM} = -10V	-2	-3.1	mA
V _{THB} Input Balance	I _{OUT} = 200 μA, V _{OUT} ≥ V _{CC} - 1.2V, R _S = 500Ω, (Note 5)	-7V ≤ V _{CM} ≤ 7V	0.1	0.4	V
		I _{OUT} = 1.6 mA, V _{OUT} ≤ 0.5V, R _S = 500Ω, (Note 5)	-7V ≤ V _{CM} ≤ 7V	-0.1	-0.4
V _{OH} Logical "1" Output Voltage	I _{OUT} = -200 μA, V _{DIFF} = 1V	V _{CC} - 1.2	V _{CC} - 0.75		V
V _{OL} Logical "0" Output Voltage	I _{OUT} = 1.6 mA, V _{DIFF} = -1V		0.25	0.5	V
I _{CC} Power Supply Current	15V ≤ V _{CM} ≤ -15V, V _{DIFF} = -0.5V (Both Receivers)	V _{CC} = 5.5V	8	15	mA
		V _{CC} = 15V	15	30	mA
I _{IN(1)} Logical "1" Strobe Input Current	V _{STROBE} = 15V, V _{DIFF} = 3V		15	100	μA
I _{IN(0)} Logical "0" Strobe Input Current	V _{STROBE} = 0V, V _{DIFF} = -3V		-0.5	-100	μA
V _{IH} Logical "1" Strobe Input Voltage	V _{OL} ≤ 0.5V, I _{OUT} = 1.6 mA	V _{CC} = 5V	3.5	2.5	V
		V _{CC} = 10V	8.0	5.0	V
		V _{CC} = 15V	12.5	7.5	V
V _{IL} Logical "0" Strobe Input Voltage	V _{OH} = V _{CC} - 1.2V, I _{OUT} = -200 μA	V _{CC} = 5V	2.5	1.5	V
		V _{CC} = 10V	5.0	2.0	V
		V _{CC} = 15V	7.5	2.5	V
I _{OS} Output Short-Circuit Current	V _{OUT} = 0V, V _{CC} = 15V, V _{STROBE} = 0V, (Note 4)	-5	-20	-40	mA

Switching Characteristics V_{CC} = 5V, T_A = 25°C

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd0(D)} Differential Input to "0" Output	C _L = 50 pF		60	100	ns
t _{pd1(D)} Differential Input to "1" Output	C _L = 50 pF		100	150	ns
t _{pd0(S)} Strobe Input to "0" Output	C _L = 50 pF		30	70	ns
t _{pd1(S)} Strobe Input to "1" Output	C _L = 50 pF		100	150	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

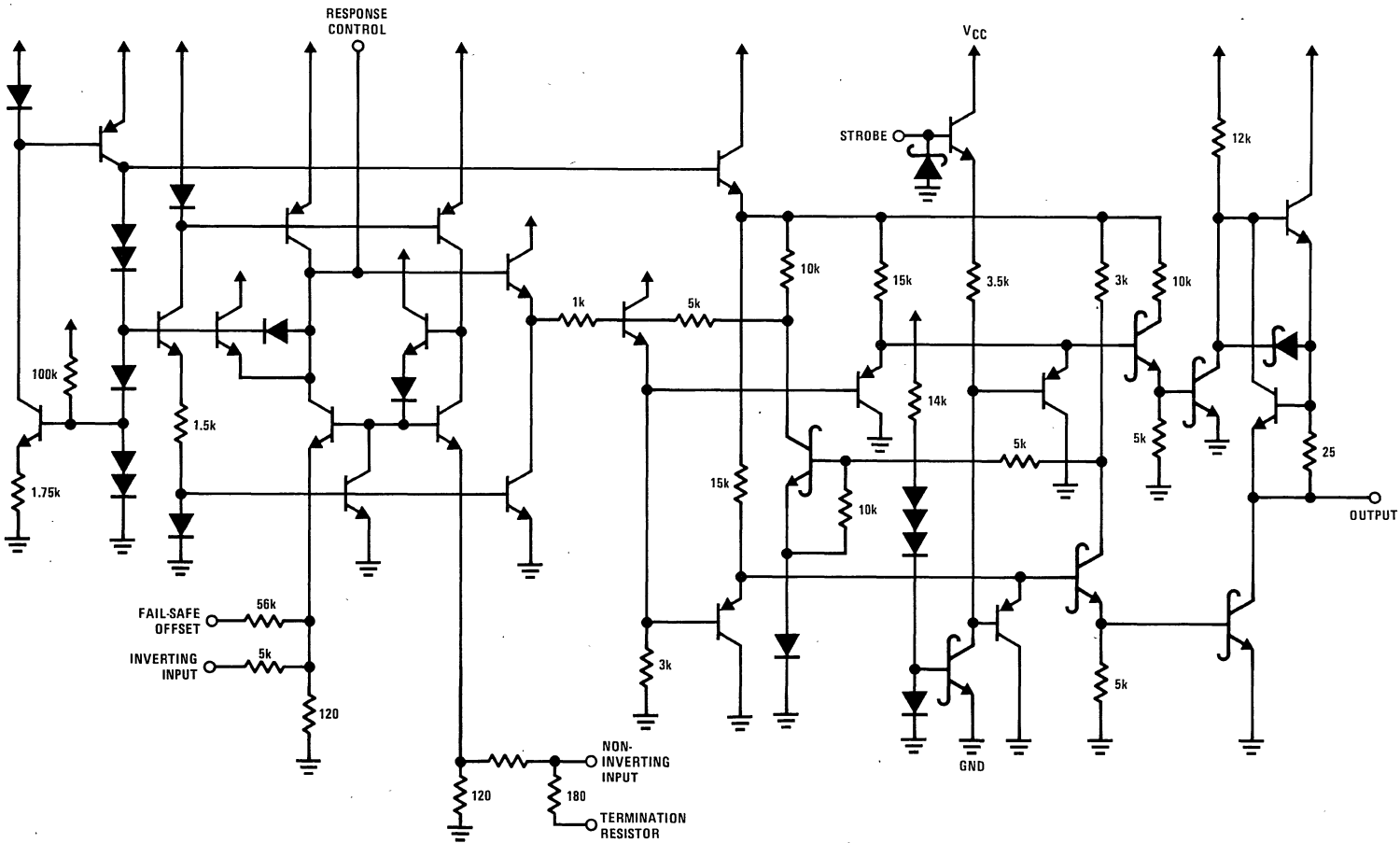
Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS78C120 and across the 0°C to +70°C range for the DS88C120. All typical values are for T_A = 25°C, V_{CC} = 5V and V_{CM} = 0V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: Refer to EIA-RS422 for exact conditions.

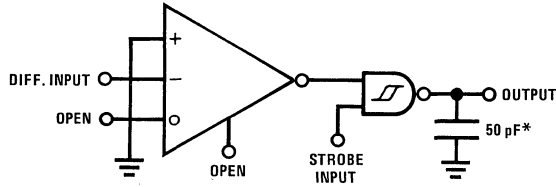
Schematic Diagram (1/2 Circuit Shown)



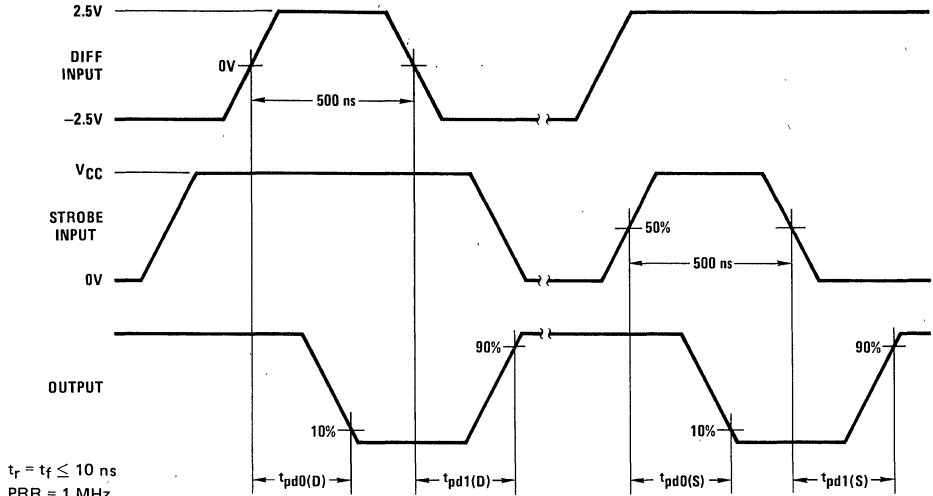
1-111

AC Test Circuit and Switching Time Waveforms

Differential and Strobe Input Signal



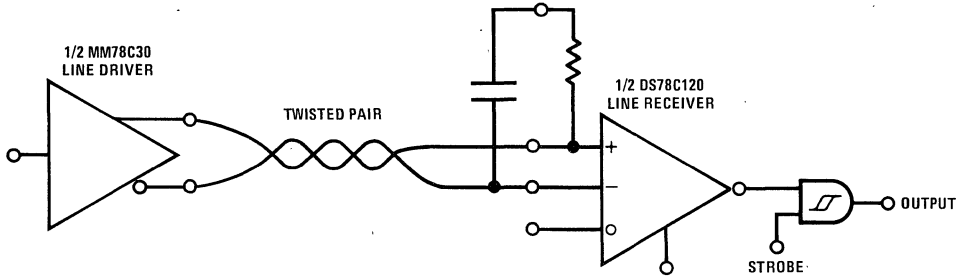
*Includes probe and test fixture capacitance



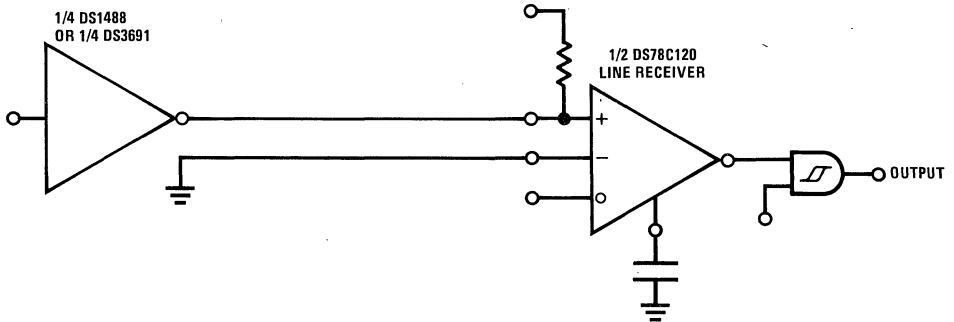
Note. Optimum switching response is obtained by minimizing stray capacitance on Response Control pin (no external connection).

Application Hints

Balanced Data Transmission

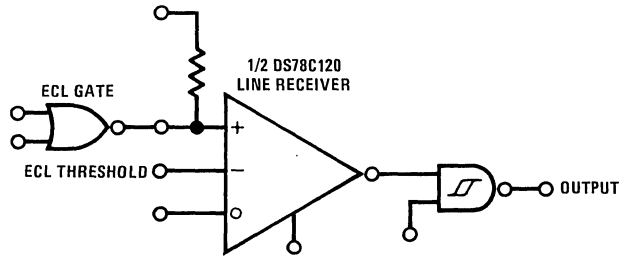
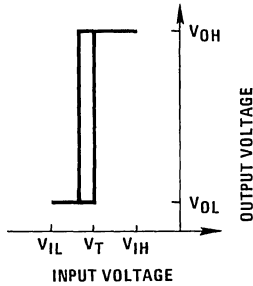


Unbalanced Data Transmission



Application Hints (Continued)

Logic Level Translator



The DS78C120/DS88C120 may be used as a level translator to interface between $\pm 12V$ MOS, ECL, TTL and CMOS. To configure, bias either input to a voltage equal to 1/2 the voltage of the input signal, and the other input to the driving gate.

LINE DRIVERS

Line drivers which will interface with the DS78C120/DS88C120 are listed below.

Balanced Drivers

DS26LS31	Quad RS422 Line Driver
MM87C30, MM88C30	Dual CMOS
DS7830, DS8830	Dual TTL
DS7831, DS8831	Dual TRI-STATE [®] TTL
DS7832, DS8832	Dual TRI-STATE TTL
DS1691, DS3691	Quad RS423/Dual RS422 TTL
DS1692, DS3692	Quad RS423/Dual TRI-STATE RS422 TTL
DS3587, DS3487	Quad TRI-STATE RS422

Unbalanced Drivers

DS1488	Quad RS232
DS75150	Dual RS232

RESPONSE CONTROL AND HYSTERESIS

In unbalanced (RS232/RS423) applications it is recommended that the rise time and fall time of the line driver be controlled to reduce cross-talk. Elimination of switching noise is accomplished in the DS78C120/DS88C120 by the 50 mV of hysteresis incorporated in the output gate. This eliminates the oscillations which may appear in a line receiver due to the input signal slowly varying about the threshold level for extended periods of time.

High frequency noise which is superimposed on the input signal which may exceed 50 mV can be reduced in amplitude by filtering the device input. On the DS78C120/DS88C120, a high impedance response control pin in the input amplifier is available to filter the input signal without affecting the termination impedance of the transmission line. Noise pulse width rejection vs the value of the response control capacitor is shown in *Figures 1 and 2*. This combination of filters followed by hysteresis will optimize performance in a worse case noise environment.

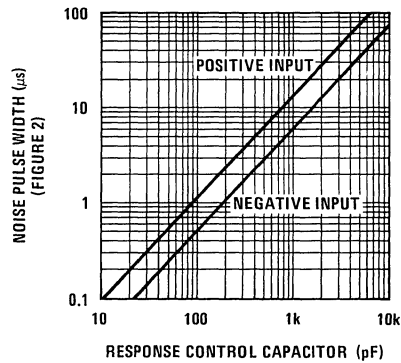


FIGURE 1. Noise Pulse Width vs Response Control Capacitor

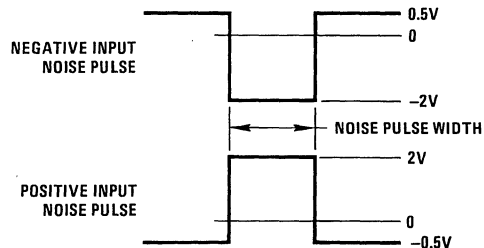
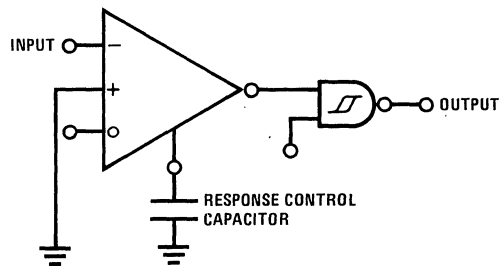


FIGURE 2



Application Hints (Continued)

TRANSMISSION LINE TERMINATION

On a transmission line which is electrically long, it is advisable to terminate the line in its characteristic impedance to prevent signal reflection and its associated noise/cross-talk. A 180Ω termination resistor is provided in the DS78C120/DS88C120 line receiver. To use the termination resistor, connect pins 2 and 3 together and pins 13 and 14 together. The 180Ω resistor provides a good compromise between line reflections, power dissipation in the driver, and IR drop in the transmission line. If power dissipation and IR drop are still a concern, a capacitor may be connected in series with the resistor to minimize power loss.

The value of the capacitor is recommended to be the line length (time) divided by 3 times the resistor value. Example: if the transmission line is 1,000 feet long, (approximately 1000 ns) the capacitor value should be 1852 pF. For additional application details, refer to application notes AN-22 and AN-108 in the National Semiconductor Interface Data Book.

FAIL-SAFE OPERATION

Communication systems require elements of a system to detect the presence of signals in the transmission lines, and it is desirable to have the system shut-down in a fail-safe mode if the transmission line is open or short. To facilitate the detection of input opens or shorts, the DS78C120/DS88C120 incorporates an input threshold voltage offset. This feature will force the line receiver to a specific logic state if presence of either fault is a condition.

Given that the receiver input threshold is ± 200 mV, an input signal greater than ± 200 mV insures the receiver will be in a specific logic state. When the offset control input (pins 1 and 15) is connected to $V_{CC} = 5V$, the

input thresholds are offset from 200 mV to 700 mV, referred to the non-inverting input, or -200 mV to -700 mV, referred to the inverting input. Therefore, if the input is open or short, the input will be greater than the input threshold and the receiver will remain in a specified logic state.

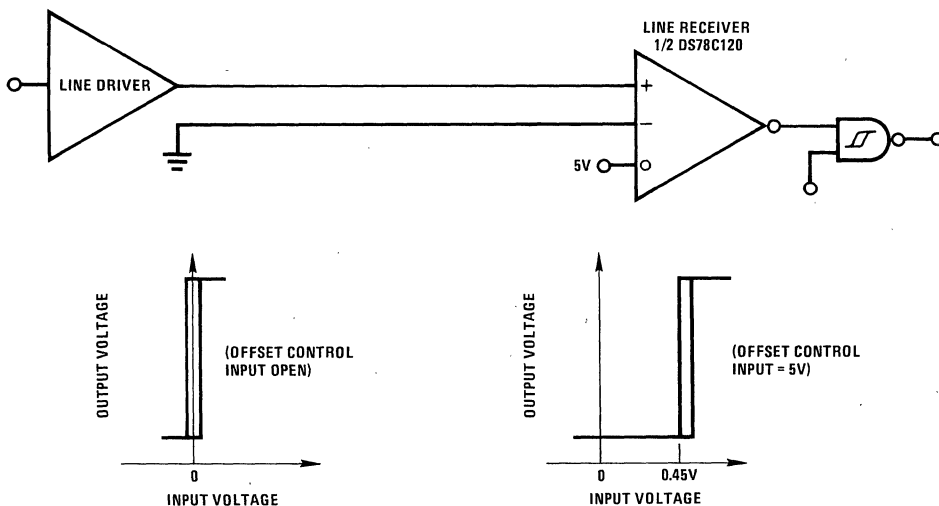
The input circuit of the receiver consists of a 5k resistor terminated to ground through 120Ω on both inputs. This network acts as an attenuator, and permits operation with common-mode input voltages greater than $\pm 15V$. The offset control input is actually another input to the attenuator, but its resistor value is 56k. The offset control input is connected to the inverting input side of the attenuator, and the input voltage to the amplifier is the sum of the inverting input plus 0.09 times the voltage on the offset control input. When the offset control input is connected to 5V the input amplifier will see $V_{IN}(\text{INVERTING}) + 0.45V$ or $V_{IN}(\text{INVERTING}) + 0.9V$ when the control input is connected to 10V. The offset control input will not significantly affect the differential performance of the receiver over its common-mode operating range, and will not change the input impedance balance of the receiver.

It is recommended that the receiver be terminated (500Ω or less) to insure it will detect an open circuit in the presence of noise.

The offset control can be used to insure fail-safe operation for unbalanced interface (RS423) or for balanced interface (RS422) operation.

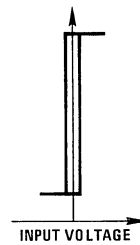
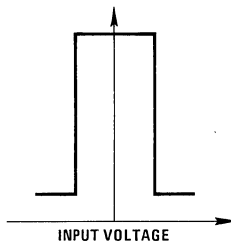
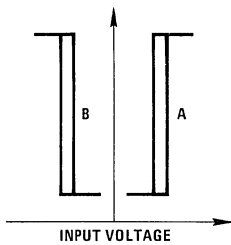
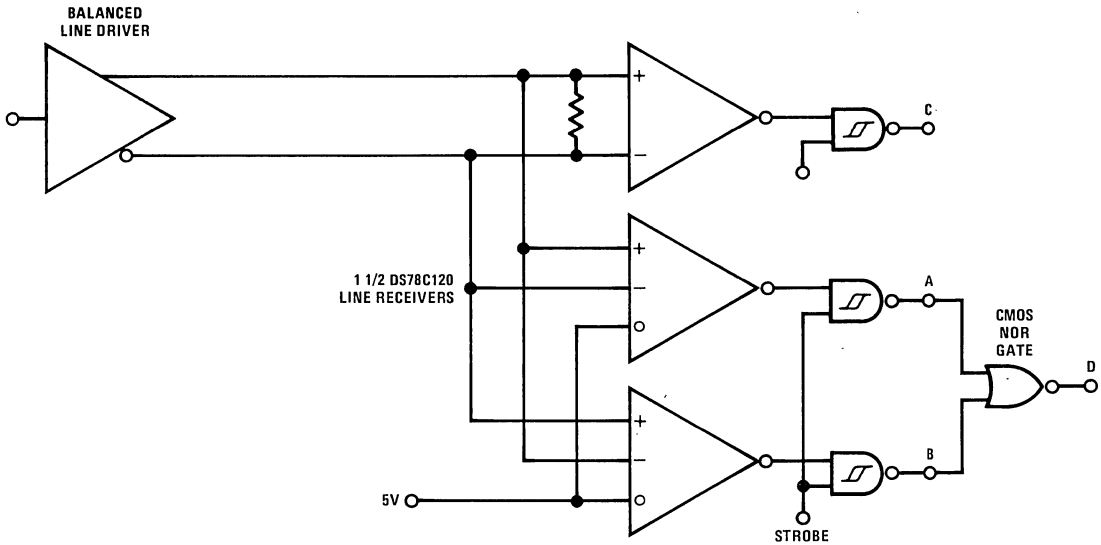
For unbalanced operation, the receiver would be in an indeterminate logic state if the offset control input was open. Connecting the offset to 5V offsets the receiver threshold 0.45V. The output is forced to a logic zero state if the input is open or short.

Unbalanced RS423 and RS232 Fail-Safe



Application Hints (Continued)

Balanced RS422 Fail-Safe



For balanced operation with inputs short or open, receiver C will be in an indeterminate logic state. Receivers A and B will be in a logic zero state allowing the NOR gate to detect the short or open condition. The strobe will disable receivers A and B and may therefore be used to sample the fail-safe detector. Another method of fail-safe detection consists of filtering the output of the NOR gate D so it would not indicate a fault condition when receiver inputs pass through the threshold region, generating an output transient.

In a communications system, only the control signals are required to detect input fault conditions. Advantages of a balanced data transmission system over an unbalanced transmission system are:

1. High noise immunity
2. High data ratio
3. Long line lengths

Truth Table (For Balanced Fail-Safe)

INPUT	STROBE	A-OUT	B-OUT	C-OUT	D-OUT
0	1	0	1	0	0
1	1	1	0	1	0
X	1	0	0	X	1
0	0	1	1	0	0
1	0	1	1	0	0
X	0	1	1	0	0

DS78LS120/DS88LS120 Dual Differential Line Receiver (Noise Filtering and Fail-Safe)

General Description

The DS78LS120 and DS88LS120 are high performance, dual differential, TTL compatible line receivers for both balanced and unbalanced digital data transmission. The inputs are compatible with EIA, Federal and MIL standards.

The line receiver will discriminate a ± 200 mV input signal over a common-mode range of ± 10 V and a ± 300 mV signal over a range of ± 15 V.

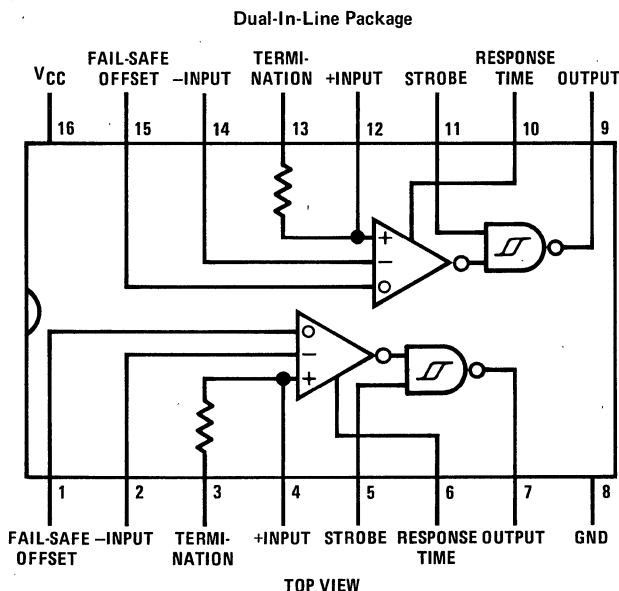
Circuit features include hysteresis and response control for applications where controlled rise and fall times and/or high frequency noise rejection are desirable. Threshold offset control is provided for fail-safe detection, should the input be open or short. Each receiver includes an optional 180Ω terminating resistor and the output gate contains a logic strobe for time discrimination. The DS78LS120 is specified over a -55°C to $+125^\circ\text{C}$ temperature range and the DS88LS120 from 0°C to $+70^\circ\text{C}$.

Input specifications meet or exceed those of the popular DS7820/DS8820 line receiver.

Features

- Meets EIA Standards RS232-C, RS422 and RS423, Federal Standards 1020, 1030 and MIL-188-114
- Input voltage range of ± 15 V (differential or common-mode)
- Separate strobe input for each receiver
- 5k typical input impedance
- Optional 180Ω termination resistor
- 50 mV input hysteresis
- 200 mV input threshold
- Separate fail-safe mode

Connection Diagram



Order Number DS78LS120J, DS88LS120J
or DS88LS120N
See NS Package J16A or N16A



Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	±25V
Strobe Voltage	7V
Output Sink Current	50 mA
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	4.5	5.5	V
Temperature (T_A)			
DS78LS120	-55	+125	°C
DS88LS120	0	+70	°C
Common-Mode Voltage (V_{CM})	-15	+15	V

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	
V_{TH}	Differential Threshold Voltage	$I_{OUT} = -400 \mu A, V_{OUT} \geq 2.5V$	$-7V \leq V_{CM} \leq 7V$		0.06	0.2	V
			$-15V \leq V_{CM} \leq 15V$		0.06	0.3	V
V_{TL}	Differential Threshold Voltage	$I_{OUT} = 4 mA, V_{OUT} \leq 0.5V$	$-7V \leq V_{CM} \leq 7V$		-0.08	-0.2	V
			$-15V \leq V_{CM} \leq 15V$		-0.08	-0.3	V
V_{TH}	Differential Threshold Voltage	$I_{OUT} = -400 \mu A, V_{OUT} \geq 2.5V$		0.47	0.7	V	
V_{TL}	With Fail Safe Offset = 5V	$I_{OUT} = 4 mA, V_{OUT} \leq 0.5V$		-0.2	-0.42	V	
R_{IN}	Input Resistance	$-15V \leq V_{CM} \leq 15V, 0V \leq V_{CC} \leq 7V$	4	5		k Ω	
R_T	Line Termination Resistance	$T_A = 25^\circ C$	100	180	300	Ω	
R_O	Offset Control Resistance	$T_A = 25^\circ C$	42	56	70	k Ω	
I_{IND}	Data Input Current (Unterminated)	$0V \leq V_{CC} \leq 7V$	$V_{CM} = 10V$		2	3.1	mA
			$V_{CM} = 0V$		0	-0.5	mA
			$V_{CM} = -10V$		-2	-3.1	mA
V_{THB}	Input Balance	$I_{OUT} = -400 \mu A, V_{OUT} \geq 2.5V, R_S = 500\Omega, (Note\ 5)$	$-7V \leq V_{CM} \leq 7V$		0.1	0.4	V
		$I_{OUT} = 4 mA, V_{OUT} \leq 0.5V, R_S = 500\Omega, (Note\ 5)$	$-7V \leq V_{CM} \leq 7V$		-0.1	-0.4	V
V_{OH}	Logical "1" Output Voltage	$I_{OUT} = -400 \mu A, V_{DIFF} = 1V, V_{CC} = 4.5V$	2.5	3		V	
V_{OL}	Logical "0" Output Voltage	$I_{OUT} = 4 mA, V_{DIFF} = -1V, V_{CC} = 4.5V$		0.35	0.5	V	
I_{CC}	Power Supply Current	$V_{CC} = 5.5V, V_{DIFF} = -0.5V, (Both\ Receivers)$	$V_{CM} = 15V$		9	12	mA
			$V_{CM} = -15V$		10	16	mA
$I_{IN(1)}$	Logical "1" Strobe Input Current	$V_{STROBE} = 5.5V, V_{DIFF} = 3V$		1	100	μA	
$I_{IN(0)}$	Logical "0" Strobe Input Current	$V_{STROBE} = 0V, V_{DIFF} = -3V$		-290	-400	μA	
V_{IH}	Logical "1" Strobe Input Voltage	$V_{OL} \leq 0.5, I_{OUT} = 4 mA$	2.0	1.12		V	
V_{IL}	Logical "0" Strobe Input Voltage	$V_{OH} \geq 2.5V, I_{OUT} = -400 \mu A$		1.12	0.8	V	
I_{OS}	Output Short-Circuit Current	$V_{OUT} = 0V, V_{CC} = 5.5V, V_{STROBE} = 0V, (Note\ 4)$	-30	-100	-170	mA	

Switching Characteristics $V_{CC} = 5V, T_A = 25^\circ C$

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
$t_{pd(0)}$ (D)	Differential Input to "0" Output	Response Pin Open, $C_L = 15 pF, R_L = 2 k\Omega$		38	60	ns
$t_{pd(1)}$ (D)	Differential Input to "1" Output			38	60	ns
$t_{pd(0)}$ (S)	Strobe Input to "0" Output			16	25	ns
$t_{pd(1)}$ (S)	Strobe Input to "1" Output			12	25	ns

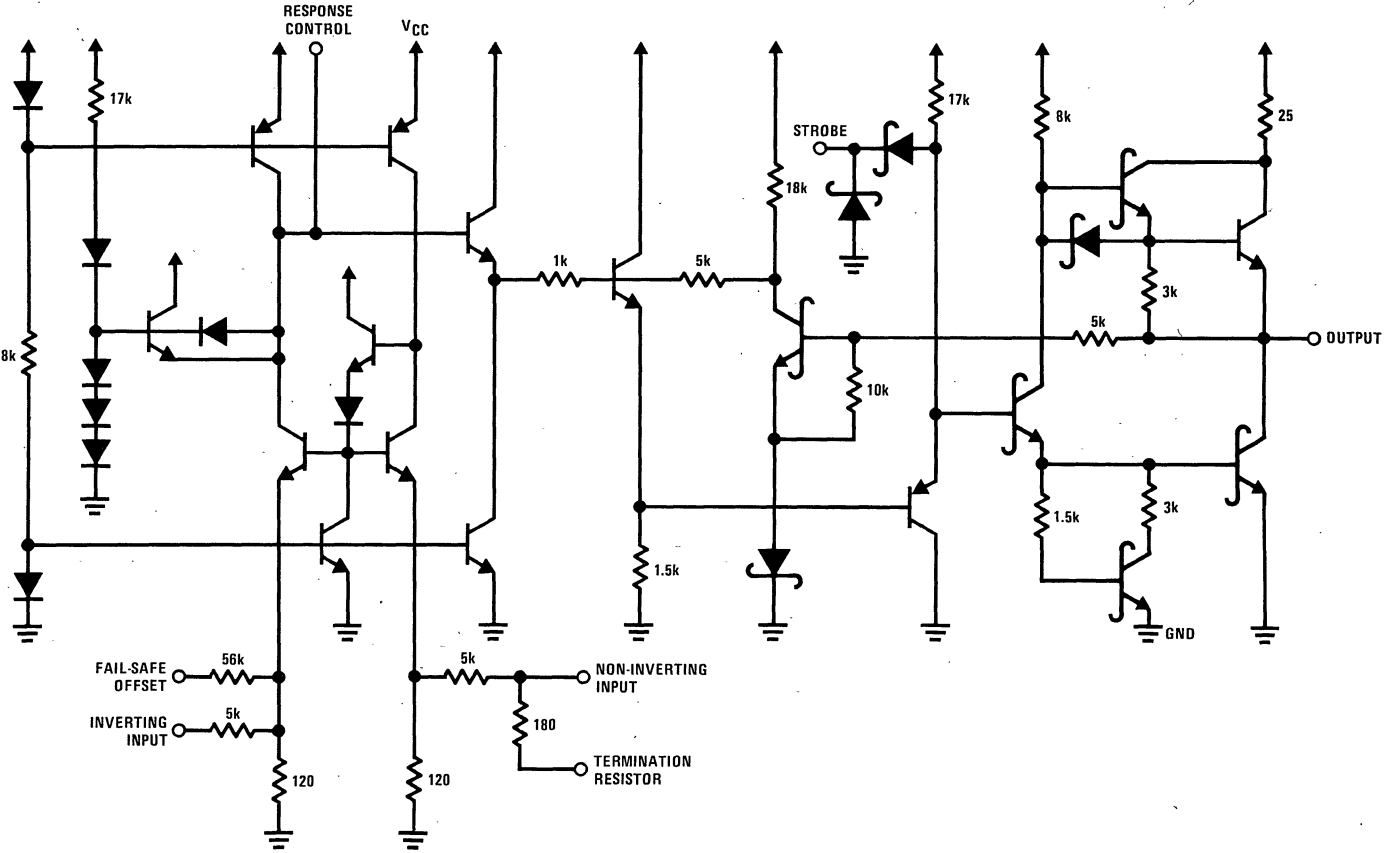
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS78LS120 and across the 0°C to +70°C for the DS88LS120. All typical values are for $T_A = 25^\circ C, V_{CC} = 5V$ and $V_{CM} = 0V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

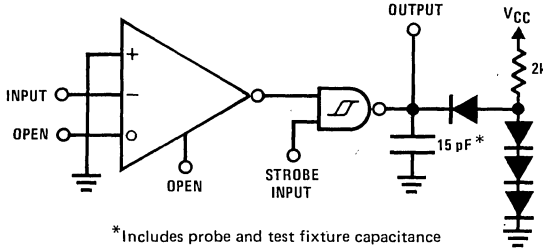
Note 4: Only one output at a time should be shorted.

Note 5: Refer to EIA-RS422 for exact conditions.

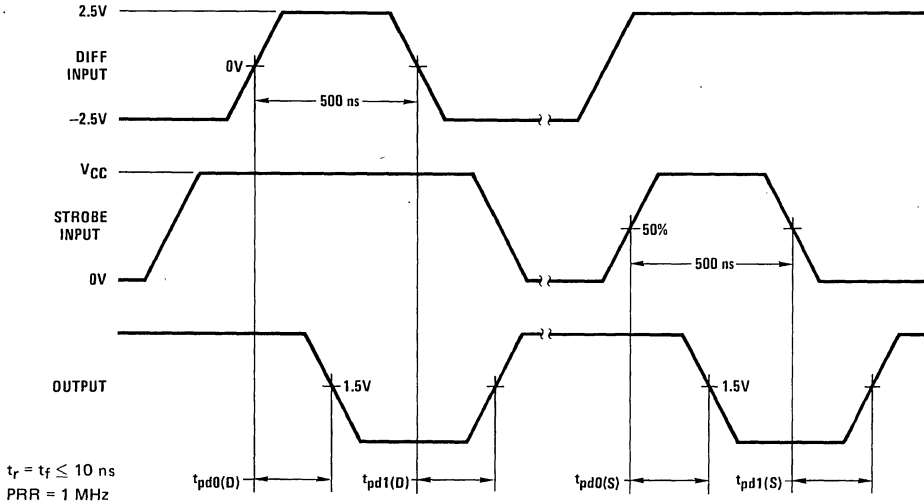


AC Test Circuit and Switching Time Waveforms

Differential and Strobe Input Signal



*Includes probe and test fixture capacitance

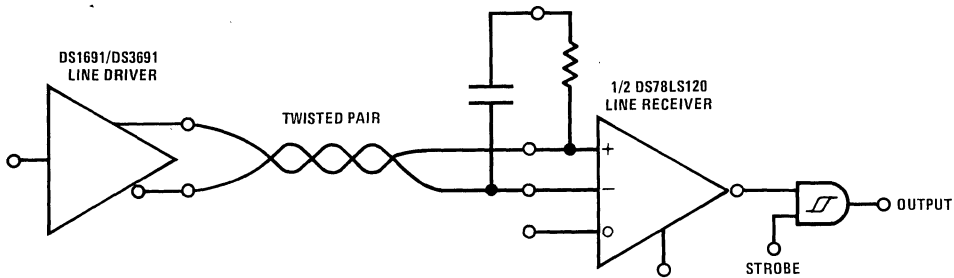


$t_r = t_f \leq 10$ ns
 PRR = 1 MHz

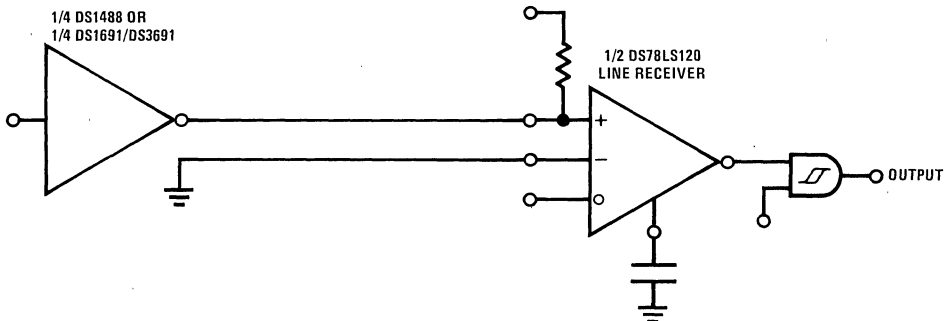
Note. Optimum switching response is obtained by minimizing stray capacitance on Response Control pin (no external connection).

Application Hints

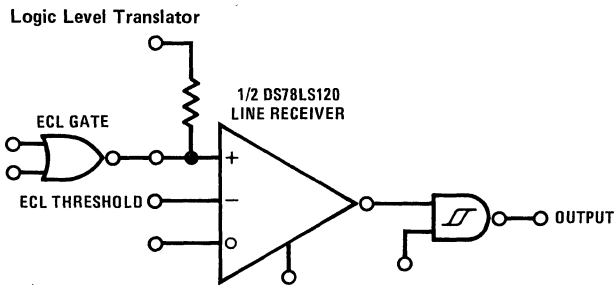
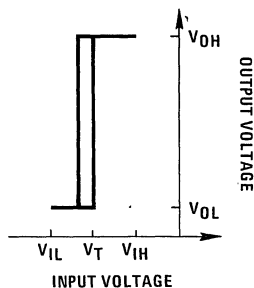
Balanced Data Transmission



Unbalanced Data Transmission



Application Hints (Continued)



The DS78LS120/DS88LS120 may be used as a level translator to interface between $\pm 12V$ MOS, ECL, TTL and CMOS. To configure, bias either input to a voltage equal to 1/2 the voltage of the input signal, and the other input to the driving gate.

LINE DRIVERS

Line drivers which will interface with the DS78LS120/DS88LS120 are listed below.

Balanced Drivers

DS26LS31	Quad RS422 Line Driver
MM87C30, MM88C30	Dual CMOS
DS7830, DS8830	Dual TTL
DS7831, DS8831	Dual TRI-STATE® TTL
DS7832, DS8832	Dual TRI-STATE TTL
DS1691, DS3691	Quad RS423/Dual RS422 TTL
DS1692, DS3692	Quad RS423/Dual TRI-STATE RS422 TTL
DS3487	Quad TRI-STATE RS422

Unbalanced Drivers

DS1488	Quad RS232
DS75150	Dual RS232

RESPONSE CONTROL AND HYSTERESIS

In unbalanced (RS232/RS423) applications it is recommended that the rise time and fall time of the line driver be controlled to reduce cross-talk. Elimination of switching noise is accomplished in the DS78LS120/DS88LS120 by the 50 mV of hysteresis incorporated in the output gate. This eliminates the oscillations which may appear in a line receiver due to the input signal slowly varying about the threshold level for extended periods of time.

High frequency noise which is superimposed on the input signal which may exceed 50 mV can be reduced in amplitude by filtering the device input. On the DS78LS120/DS88LS120, a high impedance response control pin in the input amplifier is available to filter the input signal without affecting the termination impedance of the transmission line. Noise pulse width rejection vs the value of the response control capacitor is shown in Figures 1 and 2. This combination of filters followed by hysteresis will optimize performance in a worse case noise environment.

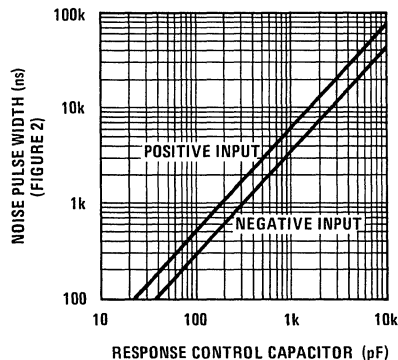


FIGURE 1. Noise Pulse Width vs Response Control Capacitor

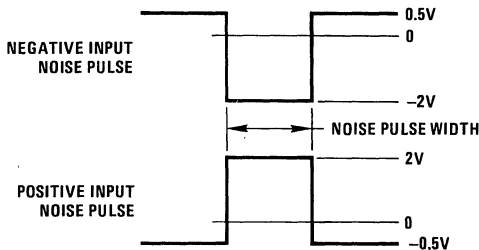
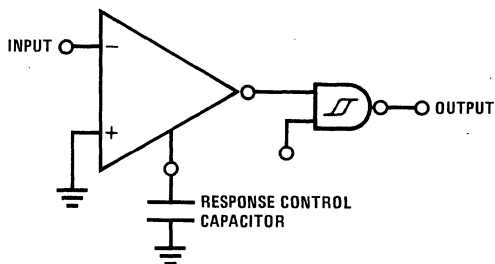


FIGURE 2

Application Hints (Continued)

TRANSMISSION LINE TERMINATION

On a transmission line which is electrically long, it is advisable to terminate the line in its characteristic impedance to prevent signal reflection and its associated noise/cross-talk. A 180Ω termination resistor is provided in the DS78LS120/DS88LS120 line receiver. To use the termination resistor, connect pins 2 and 3 together and pins 13 and 14 together. The 180Ω resistor provides a good compromise between line reflections, power dissipation in the driver, and IR drop in the transmission line. If power dissipation and IR drop are still a concern, a capacitor may be connected in series with the resistor to minimize power loss.

The value of the capacitor is recommended to be the line length (time) divided by 3 times the resistor value. Example: if the transmission line is 1,000 feet long, (approximately 1000 ns), and the termination resistor value is 180Ω , the capacitor value should be 1852 pF. For additional application details, refer to application notes AN-22 and AN-108 in the National Semiconductor Interface Data Book.

FAIL-SAFE OPERATION

Communication systems require elements of a system to detect the presence of signals in the transmission lines, and it is desirable to have the system shut-down in a fail-safe mode if the transmission line is open or short. To facilitate the detection of input opens or shorts, the DS78LS120/DS88LS120 incorporates an input threshold voltage offset. This feature will force the line receiver to a specific logic state if presence of either fault is a condition.

Given that the receiver input threshold is ± 200 mV, an input signal greater than ± 200 mV insures the receiver will be in a specific logic state. When the offset control input (pins 1 and 15) is connected to $V_{CC} = 5V$, the

input thresholds are offset from 200 mV to 700 mV, referred to the non-inverting input, or -200 mV to -700 mV, referred to the inverting input. Therefore, if the input is open or short, the input will be greater than the input threshold and the receiver will remain in a specified logic state.

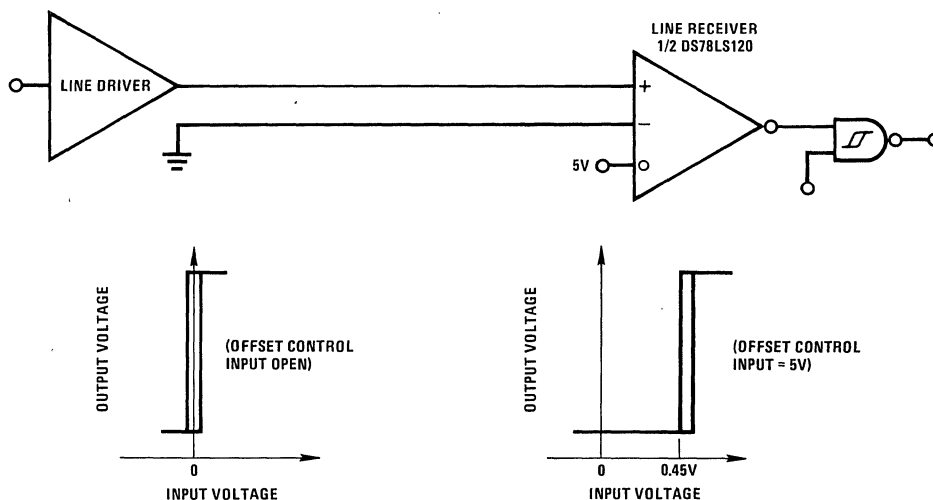
The input circuit of the receiver consists of a 5k resistor terminated to ground through 120Ω on both inputs. This network acts as an attenuator, and permits operation with common-mode input voltages greater than $\pm 15V$. The offset control input is actually another input to the attenuator, but its resistor value is 56k. The offset control input is connected to the inverting input side of the attenuator, and the input voltage to the amplifier is the sum of the inverting input plus 0.09 times the voltage on the offset control input. When the offset control input is connected to 5V the input amplifier will see $V_{IN}(\text{INVERTING}) + 0.45V$ or $V_{IN}(\text{INVERTING}) + 0.9V$ when the control input is connected to 10V. The offset control input will not significantly affect the differential performance of the receiver over its common-mode operating range, and will not change the input impedance balance of the receiver.

It is recommended that the receiver be terminated (500Ω or less) to insure it will detect an open circuit in the presence of noise.

The offset control can be used to insure fail-safe operation for unbalanced interface (RS423) or for balanced interface (RS422) operation.

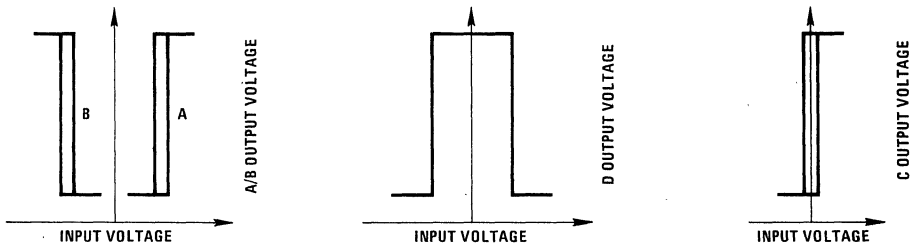
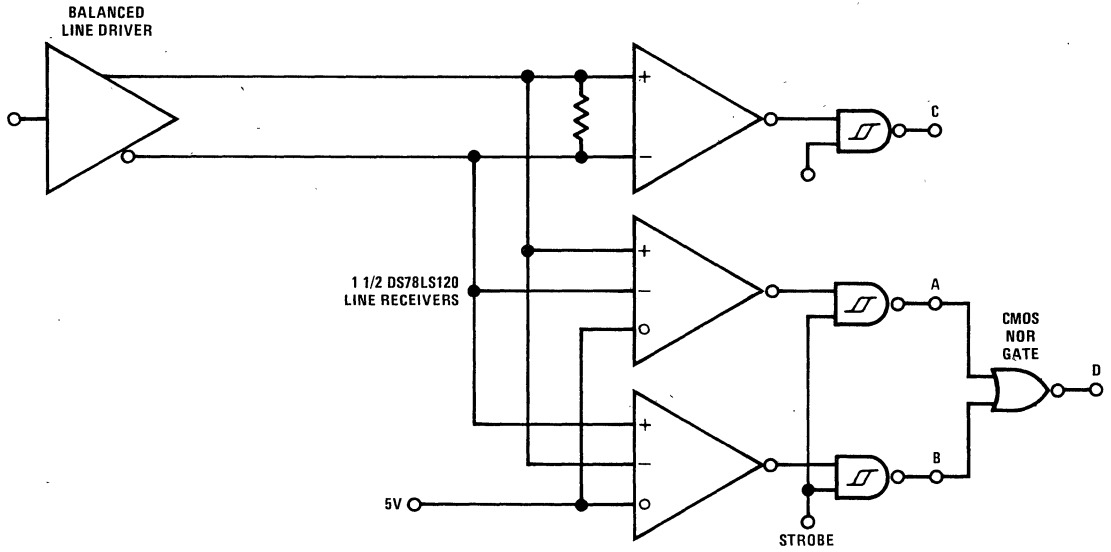
For unbalanced operation, the receiver would be in an indeterminate logic state if the offset control input was open. Connecting the offset to 5V offsets the receiver threshold 0.45V. The output is forced to a logic zero state if the input is open or short.

Unbalanced RS423 and RS232 Fail-Safe



Application Hints (Continued)

Balanced RS422 Fail-Safe



For balanced operation with inputs short or open, receiver C will be in an indeterminate logic state. Receivers A and B will be in a logic zero state allowing the NOR gate to detect the short or open condition. The strobe will disable receivers A and B and may therefore be used to sample the fail-safe detector. Another method of fail-safe detection consists of filtering the output of the NOR gate D so it would not indicate a fault condition when receiver inputs pass through the threshold region, generating an output transient.

In a communications system, only the control signals are required to detect input fault conditions. Advantages of a balanced data transmission system over an unbalanced transmission system are:

1. High noise immunity
2. High data ratio
3. Long line lengths

Truth Table (For Balanced Fail-Safe)

INPUT	STROBE	A-OUT	B-OUT	C-OUT	D-OUT
0	1	0	1	0	0
1	1	1	0	1	0
X	1	0	0	X	1
0	0	1	1	0	0
1	0	1	1	0	0
X	0	1	1	0	0



INTRODUCTION

It is frequently necessary to transmit digital data in a high-noise environment where ordinary integrated logic circuits cannot be used because they do not have sufficient noise immunity. One solution to this problem, of course, is to use high-noise-immunity logic. In many cases, this approach would require worst case logic swings of 30V, requiring high power-supply voltages. Further, considerable power would be needed to transmit these voltage levels at high speed. This is especially true if the lines must be terminated to eliminate reflections, since practical transmission lines have a low characteristic impedance.

A much better solution is to convert the ground referred digital data at the transmission end into a differential signal and transmit this down a balanced, twisted-pair line. At the receiving end, any induced noise, or voltage due to ground-loop currents, appears equally on both ends of the twisted-pair line. Hence, a receiver which responds only to the differential signal from the line will reject the undesired signals even with moderate voltage swings from the transmitter.

Figure 1 illustrates this situation more clearly. When ground is used as a signal return as in Figure 1a, the voltage seen at the receiving end will be the output voltage of the transmitter plus any noise voltage induced in the signal line. Hence, the noise immunity of the transmitter-receiver combination must be equal to the maximum expected noise from both sources.

The differential transmission scheme diagrammed in Figure 1b solves this problem. Any ground noise or voltage induced on the transmission lines will appear equally on both inputs of the receiver. The receiver responds only to the differential signal coming out of the twisted-pair line and delivers a single-ended output signal referred to the ground

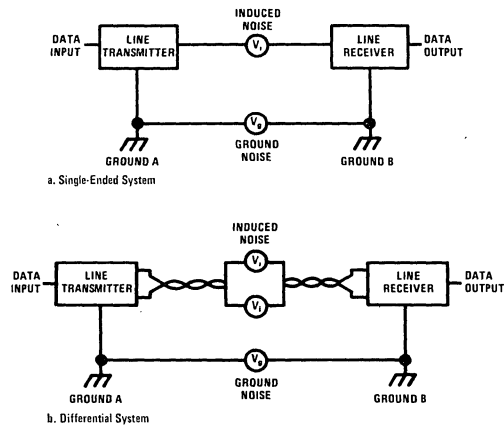


FIGURE 1. Comparing Differential and Single-Ended Data Transmission

at the receiving end. Therefore, extremely high noise immunities are not needed; and the transmitter and receiver can be operated from the same supplies as standard integrated logic circuits.

This article describes the operation and use of a line driver and line receiver for transmission systems using twisted-pair lines. The transmitter provides a buffered differential output from a DTL or TTL input signal. A four-input gate is included on the input so that the circuit can also perform logic. The receiver detects a zero crossing in the differential input voltage and can directly drive DTL or TTL integrated circuits at the receiving end. It also has strobe capability to blank out unwanted input signals. Both the transmitter and the receiver incorporate two independent units on a single silicon chip.

LINE DRIVER

Figure 2 shows a schematic diagram of the line transmitter. The circuit has a marked resemblance to a standard TTL buffer. In fact, it is possible to use a standard dual buffer as a transmitter. However, the DS7830 incorporates additional features. For one, the output is current limited to protect the driver from accidental shorts in the transmission lines. Secondly, diodes on the output clamp severe voltage transients that may be induced into the transmission lines. Finally, the circuit has internal inversion to produce a differential output signal, reducing the skew between the outputs and making the output state independent of loading.

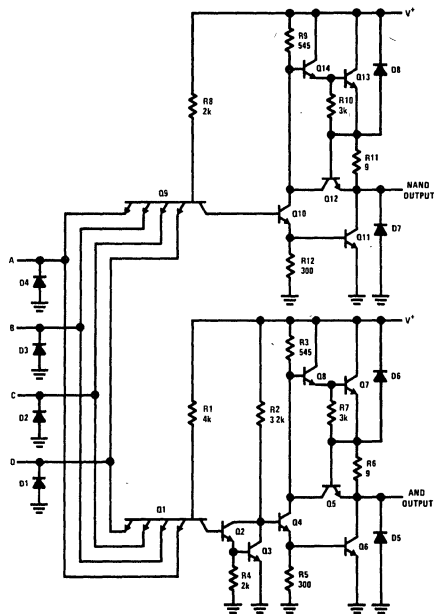


FIGURE 2. Schematic Diagram of the DS7830 Line Driver

As can be seen from the upper half of Figure 2, a quadruple-emitter input transistor, Q9, provides four logic inputs to the transmitter. This transistor drives the inverter stage formed by Q10 and Q11

to give a NAND output. A low state logic input on any of the emitters of Q9 will cause the base drive to be removed from Q10, since Q9 will be saturated by current from R8, holding the base of Q10 near ground. Hence, Q10 and Q11 will be turned off; and the output will be in a high state. When all the emitters of Q9 are at a one logic level, Q10 receives base drive from R8 through the forward biased collector-base junction of Q9. This saturates Q10 and also Q11, giving a low output state. The input voltage at which the transition occurs is equal to the sum of the emitter-base turn on voltages of Q10 and Q11 minus the saturation voltage of Q9. This is about 1.4V at 25°C.

A standard "totem-pole" arrangement is used on the output stage. When the output is switched to the high state, with Q10 and Q11 cut off, current is supplied to the load by Q13 and Q14 which are connected in a modified Darlington configuration. Because of the high compound current gain of these transistors, the output resistance is quite low and a large load current can be supplied. R10 is included across the emitter-base junction of Q13 both to drain off any collector-base leakage current in Q13 and to discharge the collector-base capacitance of Q13 when the output is switched to the low state. In the high state, the output level is approximately two diode drops below the positive supply, or roughly 3.6V at 25°C with a 5.0V supply.

With the output switched into the low state, Q10 saturates, holding the base of Q14 about one diode drop above ground. This cuts off Q13. Further, both the base current and the collector current of Q10 are driven into the base of Q11 saturating it and giving a low-state output of about 0.1V. The circuit is designed so that the base of Q11 is supplied 6 mA, so the collector can drive considerable load current before it is pulled out of saturation.

The primary purpose of R12 is to provide current to remove the stored charge in Q11 and charge its collector-base capacitance when the circuit is switched to the high state. Its value is also made enough less than R9 to prevent supply current transients which might otherwise occur* when the power supply is coming up to voltage.

*J. Kalb, "Design Considerations for a TTL Gate," *National Semiconductor TP-6*, May, 1968.

The lower half of the transmitter in Figure 2 is identical to the upper, except that an inverter stage has been added. This is needed so that an input signal which drives the output of the upper half positive will drive the lower half negative, and vice versa, producing a differential output signal. Transistors Q2 and Q3 produce the inversion. Even though the current gain is not necessarily needed, the modified Darlington connection is used to produce the proper logic transition voltage on the input of the transmitter. Because of the low load capacitance that the inverter sees when it is completely within the integrated circuit, it is extremely fast, with a typical delay of 3 ns. This minimizes the skew between the outputs.

One of the schemes used when dual buffers are employed as a differential line driver is to obtain the NAND output in the normal fashion and provide the AND output by connecting the input of the second buffer to the NAND output. Using an internal inverter has some distinct advantages over this: for one, capacitive loads which slow down the response of the NAND output will not introduce a time skew between the two outputs; secondly, line transients on the NAND output will not cause an unwanted change of state on the AND output.

Clamp diodes, D1 through D4, are added on all inputs to clamp undershoot. This undershoot and ringing can occur in TTL systems because the rise and fall times are extremely short.

Output-current limiting is provided by adding a resistor and transistor to each of the complementary outputs. Referring again to Figure 2, when the current on the NAND output increases to a value where the voltage drop across R11 is sufficient to turn on Q12, the short circuit protection comes into effect. This happens because further increases in output current flow into the base of Q12 causing it to remove base drive from Q14 and, therefore, Q13. Any substantial increase in output current will then cause the output voltage to collapse to zero. Since the magnitude of the short circuit depends on the emitter base turn-on voltage of Q12, this current has a negative temperature coefficient. As the chip temperature increases from power dissipation, the available short circuit current is reduced. The current limiting also serves to control the current transient that occurs when

the output is going through a transition with both Q11 and Q13 turned on.

The AND output is similarly protected by R6 and Q5, which limit the maximum output current to about 100 mA, preventing damage to the circuit from shorts between the outputs and ground.

The current limiting transistors also serve to increase the low state output current capability under severe transient conditions. For example, when the current into the NAND output becomes so high as to pull Q11 out of saturation, the output voltage will rise to two diode drops above ground. At this voltage, the collector-base junction of Q12 becomes forward biased and supplies additional base drive to Q11 through Q10 which is saturated. This minimizes any further increase in output voltage.

When either of the outputs are in the high state, they can drive a large current towards ground without a significant change in output voltage. However, noise induced on the transmission line which tries to drive the output positive will cut it off since it cannot sink current in this state. For this reason, D6 and D8 are included to clamp the output and keep it from being driven much above the supply voltage, as this could damage the circuit.

When the output is in a low state, it can sink a lot of current to clamp positive-going induced voltages on the transmission line. However, it cannot source enough current to eliminate negative-going transients so D5 and D7 are included to clamp those voltages to ground.

It is interesting to note that the voltage swing produced on one of the outputs when the clamp diodes go into conduction actually increases the differential noise immunity. For example with no induced common mode current, the low-state output will be a saturation voltage above ground while the high output will be two diode drops below the positive supply voltage. With positive-going common mode noise on the line, the low output remains in saturation; and the high output is clamped at a diode drop above the positive supply. Hence, in this case, the common mode noise increases the differential swing by three diode drops.

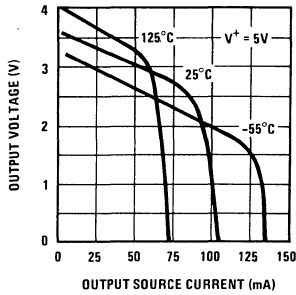


FIGURE 3. High State Output Voltage as a Function of Output Current

Having explained the operation of the line driver, it is appropriate to look at the performance in more detail. Figure 3 shows the high-state output characteristics under load. Over the normal range of output currents, the output resistance is about 10Ω . With higher output currents, the short circuit protection is activated, causing the output voltage to drop to zero. As can be seen from the figure, the short-circuit current decreases at higher temperatures to minimize the possibility of overheating the integrated circuit.

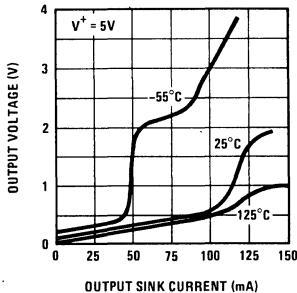


FIGURE 4. Low-State Output Current as a Function of Output Current

Figure 4 is a similar graph of the low-state output characteristics. Here, the output resistance is about 5Ω with normal values of output current. With larger currents, the output transistor is pulled out of saturation; and the output voltage increases. This is most pronounced at -55°C where the transistor current gain is the lowest. However, when the output voltage rises about two diode drops above ground, the collector-base junction of the current-limit transistor becomes forward biased,

providing additional base drive for the output transistor. This roughly doubles the current available for clamping positive common-mode transients on the twisted-pair line. It is interesting to note that even though the output level increases to about 2V under this condition, the differential noise immunity does not suffer because the high-state output also increases by about 3V with positive going common-mode transients.

It is clear from the figure that the low state output current is not effectively limited. Therefore, the device can be damaged by shorts between the output and the 5V supply. However, protection against shorts between outputs or from the outputs to ground is provided by limiting the high-state current.

The curves in Figures 3 and 4 demonstrate the performance of the line driver with large, capacitively-coupled common-mode transients, or under

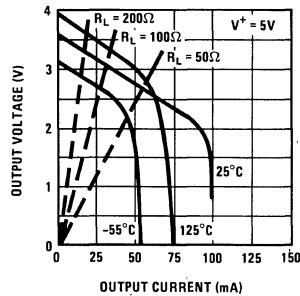


FIGURE 5. Differential Output Voltage as a Function of Differential Output Current

gross overload conditions. Figure 5 shows the ability of the circuit to drive a differential load: that is, the transmission line. It can be seen that for output currents less than 35 mA, the output resistance is approximately 15Ω . At both temperature extremes, the output falls off at high currents. At high temperatures, this is caused by current limiting of the high output state. At low temperatures, the falloff of current gain in the low-state output transistor produces this result.

Load lines have been included on the figure to show the differential output with various load resistances. The output swing can be read off from the intersection of the output characteristic with the load line. The figure shows that the driver can easily handle load resistances greater than 100Ω .

This is more than adequate for practical, twisted-pair lines.

Figure 6 shows the no load power dissipation, for one-half of the dual line driver, as a function of frequency. This information is important for two reasons. First, the increase in power dissipation at high frequencies must be added to the excess power dissipation caused by the load to determine the total package dissipation. Second, and more important, it is a measure of the "glitch" current which flows from the positive supply to ground through the output transistors when the circuit is going through a transition. If the output stage is

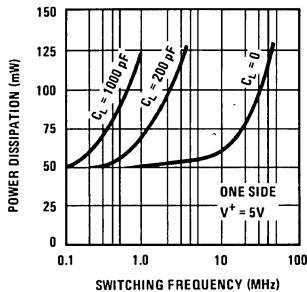


FIGURE 6. Power Dissipation as a Function of Switching Frequency

not properly designed, the current spikes in the power supplies can become quite large; and the power dissipation can increase by as much as a factor of five between 100 KHz and 10 MHz. The figure shows that, with no capacitive loading, the power increase with frequencies as high as 10 MHz is almost negligible. However, with large capacitive loads, more power is required.

The line receiver is designed to detect a zero crossing in the differential output of the line driver. Therefore, the propagation time of the driver is measured as the time difference between the application of a step input and the point where the differential output voltage crosses zero. A plot of the propagation time over temperature is shown in Figure 7. This delay is added directly to the propagation time of the transmission line and the delay of the line receiver to determine the total data-propagation time. However, in most cases, the delay of the driver is small, even by comparison to the uncertainties in the other delays.

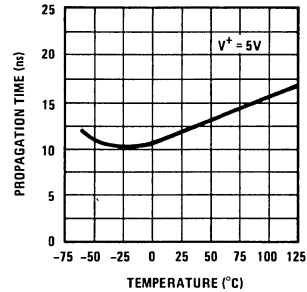


FIGURE 7. Propagation Time as a Function of Temperature

To summarize the characteristics of the DS7830 line driver, the input interfaces directly with standard TTL circuits. It presents a load which is equivalent to a fan out of 3 to the circuit driving it, and it operates from the 5.0V, $\pm 10\%$ logic supplies. The output can drive low impedance lines down to 50Ω and capacitive loads up to 5000 pF. The time skew between the outputs is minimized to reduce radiation from the twisted-pair lines, and the circuit is designed to clamp common mode transients coupled into the line. Short circuit protection is also provided. The integrated circuit consists of two independent drivers fabricated on a 41×53 mil-square die using the standard TTL process. A photomicrograph of the chip is shown in Figure 8.

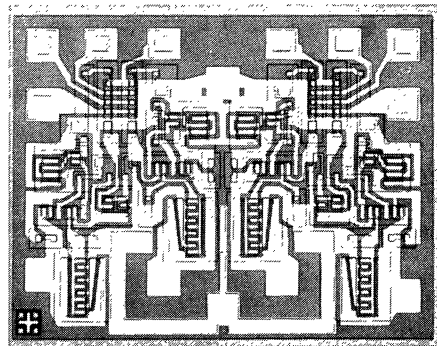


FIGURE 8. Photomicrograph of the DS7830 Dual Line Driver

LINE RECEIVER

As mentioned previously, the function of the line receiver is to convert the differential output signal of the line driver into a single ended, ground-referred signal to drive standard digital circuits on the receiving end. At the same time it must reject the common mode and induced noise on the transmission line.

Normally this would not be too difficult a task because of the large signal swings involved. However, it was considered important that the receiver operate from the +5V logic supply without requiring additional supply voltages, as do most other line receiver designs. This complicates the situation because the receiver must operate with $\pm 15V$ input signals which are considerably greater than the operating supply voltage.

The large common mode range over which the circuit must work can be reduced with an attenuator on the input of the receiver. In this design, the input signal is attenuated by a factor of 30. Hence, the $\pm 15V$ common mode voltage is reduced to $\pm 0.5V$, which can be handled easily by circuitry operating from a 5V supply. However, the differential input signal, which can go down as low as $\pm 2.4V$ in the worst case, is also reduced to $\pm 80 mV$. Hence, it is necessary to employ a fairly accurate zero crossing detector in the receiver.

System requirements dictated that the threshold inaccuracy introduced by the zero crossing detector be less than 17 mV. In principle, this accuracy requirement should not pose insurmountable problems because it is a simple matter to make well matched parts in an integrated circuit.

Figure 9 shows a simplified schematic diagram of the circuit configuration used for the line receiver. The input signal is attenuated by the resistive dividers R1-R2 and R8-R3. This attenuated signal is fed into a balanced dc amplifier, operating in the common base configuration. This input amplifier, consisting of Q1 and Q2, removes the common mode component of the input signal. Further, it delivers an output signal at the collector of Q2, which is nearly equal in amplitude to the original differential input signal. This output signal is buffered by Q6 and drives an output amplifier, Q8. The output stage drives the logic load directly.

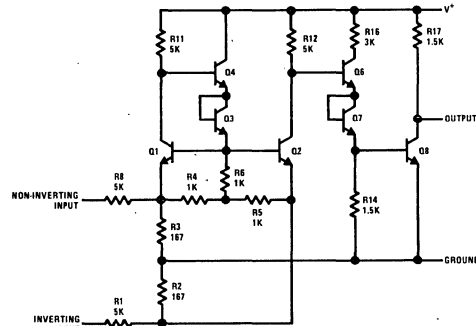


FIGURE 9. Simplified Schematic of the Line Receiver

An understanding of the circuit can be obtained by first considering the input stage. Assuming high current gains and neglecting the voltage drop across R3, the collector current of Q1 will be:

$$I_{C1} = \frac{V^+ - V_{BE1} - V_{BE3} - V_{BE4}}{R11} \quad (1)$$

With equal emitter-base voltages for all transistors, this becomes:

$$I_{C1} = \frac{V^+ - 3V_{BE}}{R11} \quad (2)$$

The output voltage at the collector of Q2 will be:

$$V_{C2} = V^+ - I_{C2}R12 \quad (3)$$

When the differential input voltage to the receiver is zero, the voltages presented to the emitters of Q1 and Q2 will be equal. If Q1 and Q2 are matched devices, which is easy to arrange when they are fabricated close together on a single silicon chip, their collector currents will be equal with zero input voltage. Hence, the output voltage from Q2 can be determined by substituting (2) into (3):

$$V_{C2} = V^+ - \frac{R12}{R11} (V^+ - 3V_{BE}) \quad (4)$$

For $R_{11} = R_{12}$, this becomes:

$$V_{C2} = 3V_{BE}$$

The voltage on the base of Q6 will likewise be $3V_{BE}$ when the output is on the verge of switching from a zero to a one state. A differential input signal which causes Q2 to conduct more heavily will then make the output go high, while an input signal in the opposite direction will cause the output to saturate.

It should be noted that the balance of the circuit is not affected by absolute values of components—only by how well they match. Nor is it affected by variations in the positive supply voltage, so it will perform well with standard logic supply voltages between 4.5V and 5.5V. In addition, component values are chosen so that the collector currents of Q4 and Q6 are equal. As a result, the base currents of Q4 and Q6 do not upset the balance of the input stage. This means that circuit performance is not greatly affected by production or temperature variations in transistor current gain.

A complete schematic of the line receiver, shown in Figure 10, shows several refinements of the basic circuit which are needed to secure proper

operation under all conditions. For one, the explanation of the simplified circuit ignores the fact that the collector current of Q1 will be affected by common mode voltage developed across R3. This can give a 0.5V threshold error at the extremes of the $\pm 15V$ common mode range. To compensate for this, a separate divider, R9 and R10, is used to maintain a constant collector current in Q1 with varying common mode signals. With an increasing common mode voltage on the non-inverting input, the voltage on the emitter of Q1 will increase. Normally, this would cause the voltage across R11 to decrease, reducing the collector current of Q1. However, the increasing common mode signal also drives the top end of R11 through R9 and R10 so as to hold the voltage drop across R11 constant.

In addition to improving the common mode rejection, R9 also forces the output of the receiver into the high state when nothing is connected to the input lines. This means that the output will be in a pre-determined state when the transmission cables are disconnected.

A diode connected transistor, Q5, is also added in the complete circuit to provide strobe capability. With a logic zero on the strobe terminal, the out-

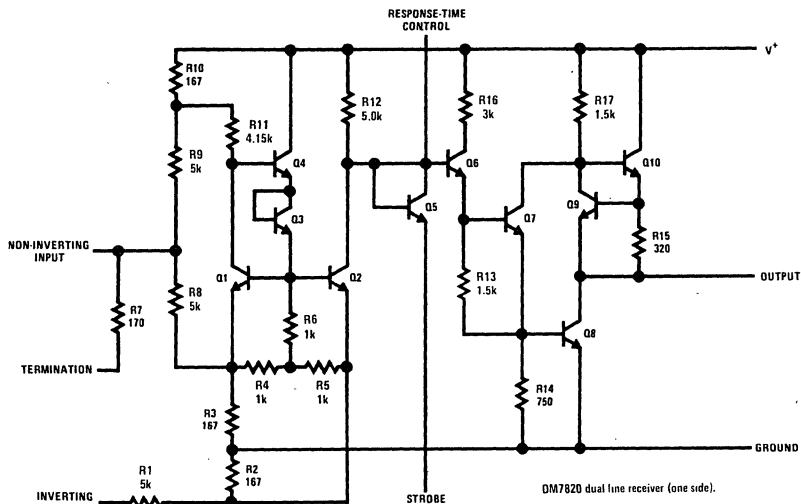


FIGURE 10. Complete Schematic of One Half of the DS7820 Line Receiver

put will be high no matter what the input signal is. With the strobe, the receiver can be made immune to any noise signals during intervals where no digital information is expected. The output state with the strobe on is also the same as the output state with the input terminals open.

The collector of Q2 is brought out so that an external capacitor can be used to slow down the receiver to where it will not respond to fast noise spikes. This capacitor, which is connected between the response-time-control terminal and ground, does not give exactly-symmetrical delays. The delay for input signals which produce a positive-going output will be less than for input signals of opposite polarity. This happens because the impedance on the collector of Q2 drops as Q6 goes into saturation, reducing the effectiveness of the capacitor.

Another difference in the complete circuit is that the output stage is improved both to provide more gain and to reduce the output resistance in the high output state. This was accomplished by adding Q9 and Q10. When the output stage is operating in the linear region, that is, on the verge of switching to either the high or the low state, Q9 and Q10 form sort of an active collector load for Q8. The current through R15 is constant at approximately 2 mA as the output voltage changes through the active region. Hence, the percentage change in the collector current of Q8 due to the voltage change across R17 is made smaller by this pre-bias current; and the effective stage gain is increased.

With the output in the high state (Q8 cut off), the output resistance is equal to R15, as long as the load current is less than 2 mA. When the load current goes above this value, Q9 turns on; and the output resistance increases to 1.5K, the value of R17.

This particular output configuration gives a higher gain than either a standard DTL or TTL output stage. It can also drive enough current in the high state to make it compatible with TTL, yet outputs can be wire OR'ed as with DTL.

Remaining details of the circuit are that Q7 is connected as an emitter follower to make the circuit even less sensitive to transistor current gains. R16 limits the base drive to Q7 with the output saturated, while R17 limits the base drive to the output transistor, Q8. A resistor, R7, which can be used to terminate the twisted-pair line is also included on the chip. It is not connected directly

across the inputs. Instead, one end is left open so that a capacitor can be inserted in series with the resistor. The capacitor significantly reduces the power dissipation in both the line transmitter and receiver, especially in low-duty-cycle applications, by terminating the line at high frequencies but blocking steady-state current flow in the terminating resistor.

Since line receivers are generally used repetitively in a system, the DS7820 has been designed with two independent receivers on a single silicon chip. The device is fabricated on a 41 x 49 mil-square die using the standard six mask planar-epitaxial process. The processing employed is identical to that used on TTL circuits, and the design does not impose any unusual demands on the processing. It is only required that various parts within the circuit match well, but this is easily accomplished in a monolithic integrated circuit without any special effort in manufacturing. A photomicrograph of the integrated circuit chip is shown in Figure 11.

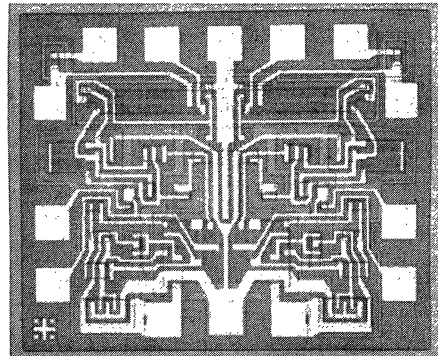


FIGURE 11. Photomicrograph of the DS7820 Dual Line Receiver

The only components in the circuit which see voltages higher than standard logic circuits are the resistors used to attenuate the input signal. These resistors, R1, R7, R8 and R9, are diffused into a separate, floating, N-type isolation tub, so that the higher voltage is not seen by any of the transistors. For a $\pm 15V$ input voltage range, the breakdown voltages required for the collector-isolation and collector-base diodes are only 15V and 19V, respectively. These breakdown voltages can be achieved readily with standard digital processing.

The purpose of the foregoing was to provide some insight into circuit operation. A more exact mathematical analysis of the device is developed in Appendix A.

RECEIVER PERFORMANCE

The characteristics of the line receiver are described graphically in Figures 12 through 18. Figure 12 illustrates the effect of supply voltage variations on the threshold accuracy. The upper curve gives the differential input voltage required to hold the output at 2.5V while it is supplying 200 μ A to the digital load. The lower curve shows the differential input needed to hold the output at 0.4V while it sinks 3.5 mA from the digital load. This load corresponds to a worst case fanout of 2 with either DTL or TTL integrated circuits. The data shows that the threshold accuracy is only affected by ± 60 mV for a $\pm 10\%$ change in supply voltage. Proper operation can be secured over a wider range of supply voltages, although the error becomes excessive at voltages below 4V.

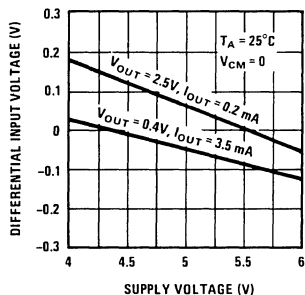


FIGURE 12. Differential Input Voltage Required for High or Low Output as a Function of Supply Voltage

Figure 13 is a similar plot for varying common mode input voltage. Again the differential input voltages are given for high and low states on the output with a worst case fanout of 2. With precisely matched components within the integrated circuit, the threshold voltage will not

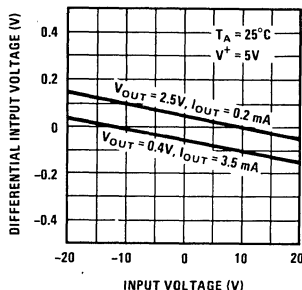


FIGURE 13. Differential Input Voltage Required for High or Low Output as a Function of Common Mode Voltage

change with common mode voltage. The mismatches typically encountered give a threshold voltage change of ± 100 mV over a ± 20 V common mode range. This change can have either a positive slope or a negative slope.

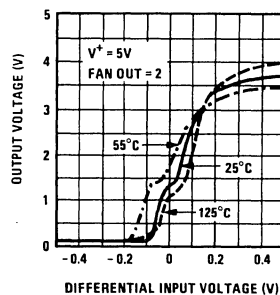


FIGURE 14. Voltage Transfer Function

The transfer function of the circuit is given in Figure 14. The loading is for a worst case fanout of 2. The digital load is not linear, and this is reflected as a non-linearity in the transfer function which occurs with the output around 1.5V. These transfer characteristics show that the only significant effect of temperature is a reduction in the positive swing at -55°C . However, the voltage available remains well above the 2.5V required by digital logic.

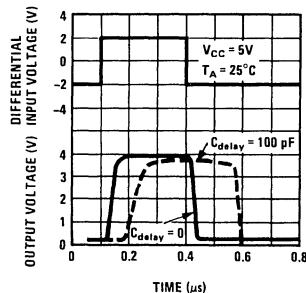


FIGURE 15. Response Time With and Without an External Delay Capacitor

Figure 15 gives the response time, or propagation delay, of the receiver. Normally, the delay through the circuit is about 40 ns. As shown, the delay can be increased, by the addition of a capacitor between the response-time terminal and ground, to make the device immune to fast noise spikes on the input. The delay will generally be longer for negative going outputs than for positive going outputs.

Under normal conditions, the power dissipated in the receiver is relatively low. However, with large common mode input voltages, dissipation increases markedly, as shown in Figure 16. This is of little consequence with common mode transients, but the increased dissipation must be taken into account when there is a dc difference between the grounds of the transmitter and the receiver. It is important to note that Figure 16 gives the dissipation for one half the dual receiver. The total package dissipation will be twice the values given when both sides are operated under identical conditions.

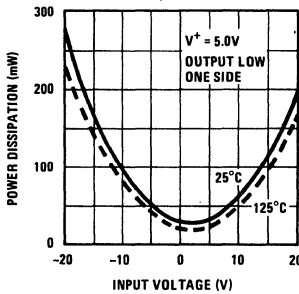


FIGURE 16. Internal Power Dissipation as a Function of Common Mode Input Voltage

Figure 17 shows that the power supply current also changes with common mode input voltage due to the current drawn out of or fed into the supply through R9. The supply current reaches a maximum with negative input voltages and can actually reverse with large positive input voltages. The figure also shows that the supply current with the output switched into the low state is about 3 mA higher than with a high output.

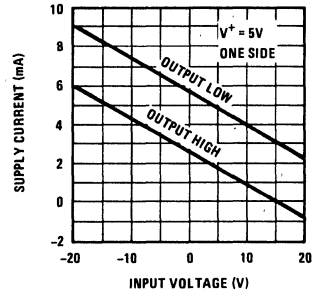


FIGURE 17. Power Supply Current as a Function of Common Mode Input Voltage

The variation of the internal termination resistance with temperature is illustrated in Figure 18. Taking into account the initial tolerance as well as the change with temperature, the termination resistance is by no means precise. Fortunately, in most cases, the termination resistance can vary appreciably without greatly affecting the characteristics of the transmission line. If the resistor tolerance is a problem, however, an external resistor can be used in place of the one provided within the integrated circuit.

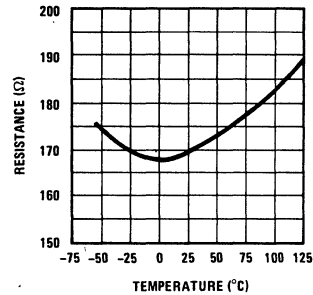


FIGURE 18. Variation of Termination Resistance With Temperature

DATA TRANSMISSION

The interconnection of the DS7830 line driver with the DS7820 line receiver is shown in Figure 19. With the exception of the transmission line, the design is rather straightforward. Connections on the input of the driver and the output or strobe of the receiver follow standard design rules for DTL or TTL integrated logic circuits. The load presented by the driver inputs is equal to 3 standard digital loads, while the receiver can drive a worst-case fanout of 2. The load presented by the receiver strobe is equal to one standard load.

The purpose of C1 on the receiver is to provide dc isolation of the termination resistor for the transmission line. This capacitor can both increase the differential noise immunity, by reducing attenuation on the line, and reduce power dissipation in both the transmitter and receiver. In some applications, C1 can be replaced with a short between Pins 1 and 2, which connects the internal termination resistor of the DS7820 directly across the line. C2 may be included, if necessary, to control the response time of the receiver, making it immune to noise spikes that may be coupled differentially into the transmission lines.

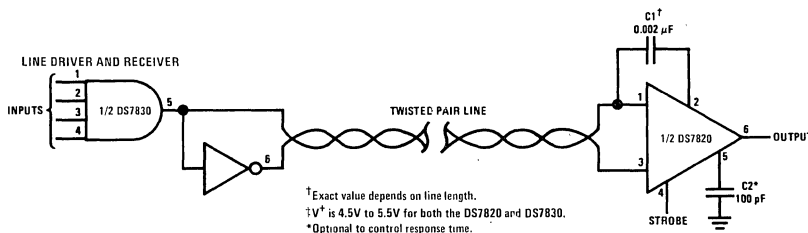


FIGURE 19. Interconnection of the Line Driver and Line Receiver

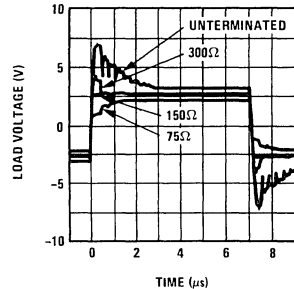


FIGURE 20. Transmission Line Response With Various Termination Resistances

The effect of termination mismatches on the transmission line is shown in Figure 20. The line was constructed of a twisted pair of No. 22 copper conductors with a characteristic impedance of approximately 170Ω . The line length was about 150 ns and it was driven directly from a DS7830 line driver. The data shows that termination resistances which are a factor of two off the nominal value do not cause significant reflections on the line. The lower termination resistors do, however, increase the attenuation.

Figure 21 gives the line-transmission characteristics with various termination resistances when a dc isolation capacitor is used. The line is identical to that used in the previous example. It can be seen that the transient response is nearly the same as a dc terminated line. The attenuation, on the other hand, is considerably lower, being the same as an unterminated line. An added advantage of using the isolation capacitor is that the dc signal current is blocked from the termination resistor which reduces the average power drain of the driver and the power dissipation in both the driver and receiver.

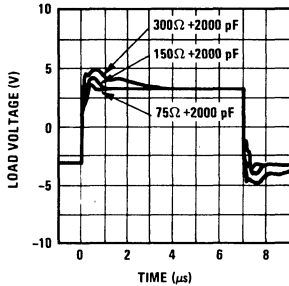


FIGURE 21. Line Response for Various Termination Resistances With a DC Isolation Capacitor

The effect of different values of dc isolation capacitors is illustrated in Figure 22. This shows that the RC time constant of the termination resistor/isolation capacitor combination should be 2 to 3 times the line delay. As before, this data was taken for a 150 ns long line.

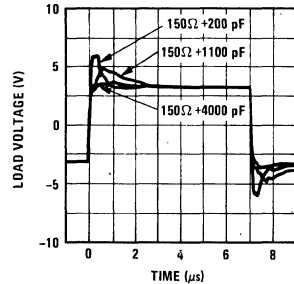
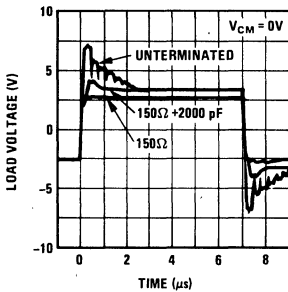
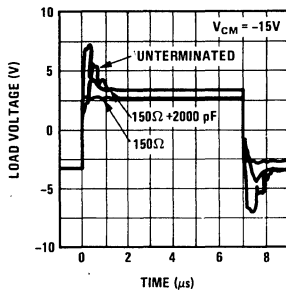


FIGURE 22. Response of Terminated Line With Different DC Isolation Capacitors

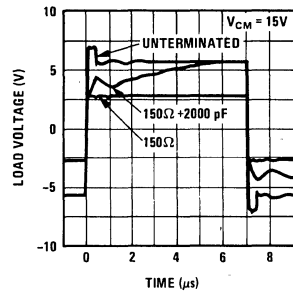
In Figure 23, the influence of a varying ground voltage between the transmitter and the receiver is shown. The difference in the characteristics arises because the source resistance of the driver is not constant under all conditions. The high output of



a. $V_{CM} = 0V$



b. $V_{CM} = -15V$



c. $V_{CM} = 15V$

FIGURE 23. Line Response With Different Terminations and Common Mode Input Voltages

the transmitter looks like an open circuit to voltages reflected from the receiving end of the transmission line which try to drive it higher than its normal dc state. This condition exists until the voltage at the transmitting end becomes high enough to forward bias the clamp diode on the 5V supply. Much of the phenomena which does not follow simple transmission-line theory is caused by this. For example, with an unterminated line, the overshoot comes from the reflected signal charging the line capacitance to where the clamp diodes are forward biased. The overshoot then decays at a rate determined by the total line capacitance and the input resistance of the receiver.

When the ground on the receiver is 15V more negative than the ground at the transmitting end, the decay with an unterminated line is faster, as shown in Figure 23b. This occurs because there is more current from the input resistor of the receiver to discharge the line capacitance. With a terminated line, however, the transmission characteristics are the same as for equal ground voltages because the terminating resistor keeps the line from getting charged.

Figure 23c gives the transmission characteristics when the receiver ground is 15V more positive than the transmitter ground. When the line is not terminated, the differential voltage swing is increased because the high output of the driver will be pulled against the clamp diodes by the common mode input current of the receiver. With a dc isolation capacitor, the differential swing will reach this same value with a time constant determined by the isolation capacitor and the input resistance of the receiver. With a dc coupled termination, the characteristics are unchanged because the differential load current is large by comparison to the common mode current so that the output transistors of the driver are always conducting.

The low output of the driver can also be pulled below ground to where the lower clamp diode con-

ducts, giving effects which are similar to those described for the high output. However, a current of about 9 mA is required to do this, so it does not happen under normal operating conditions.

To summarize, the best termination is an RC combination with a time constant approximately equal to 3 times the transmission-line delay. Even though its value is not precisely determined, the internal termination resistor of the integrated circuit can be used because the line characteristics are not greatly affected by the termination resistor.

The only place that an RC termination can cause problems is when the data transmission rate approaches the line delay and the attenuation down the line (terminated) is greater than 3 dB. This would correspond to more than 1000 ft. of twisted-pair cable with No. 22 copper conductors. Under these conditions, the noise margin can disappear with low-duty-cycle signals. If this is the case, it is best to operate the twisted-pair line without a termination to minimize transmission losses. Reflections should not be a problem as they will be absorbed by the line losses.

CONCLUSION

A method of transmitting digital information in high-noise environments has been described. The technique is a much more attractive solution than high-noise-immunity logic as it has lower power consumption, provides more noise rejection, operates from standard 5V supplies, and is fully compatible with almost all integrated logic circuits. An additional advantage is that the circuits can be fabricated with integrated circuit processes used for standard logic circuits.

APPENDIX A

LINE RECEIVER

Design Analysis

The purpose of this appendix is to derive mathematical expressions describing the operation of the line receiver. It will be shown that the performance of the circuit is not greatly affected by the absolute value of the components within the integrated circuit or by the supply voltage. Instead, it depends mostly on how well the various parts match.

The analysis will assume that all the resistors are well matched in ratio and that the transistors are likewise matched, since this is easily accomplished over a broad temperature range with monolithic construction. However, the effects of component mismatching will be discussed where important. Further, large transistor current gains will be assumed, but it will be pointed out later that this is valid for current gains greater than about 10.

A schematic diagram of the DS7820 line receiver is shown in Figure A-1. Referring to this circuit, the collector current of the input transistor is given by

$$I_{C1} = \frac{V^+ - V_{BE1} - V_{BE3} - V_{BE4}}{R9 // R10 + R11 + R3 // R8} - \frac{R3}{R4 + 2R6 + R3} \frac{V_{BE1} - \frac{R3 // R11}{R8 + R3 // R1} V_{IN}}{R9 // R10 + R11 + R3 // R8} + \frac{(V_{IN} - V^+)}{R9 + R10 // R11} \frac{R10 // R11}{R9 // R10 + R11 + R3 // R8} \quad (A. 1)$$

where V_{IN} is the common mode input voltage and $R_a // R_b$ denotes the parallel connection of the two resistors. In Equation (A. 1), $R8 = R9$, $R3 = R10$, $R10 \ll R11$, $R9 \gg R10$, $R3 \ll R11$, $R8 \gg R3$

and $\frac{R3}{R4 + 2R6 + R3} \ll 3$ so it can be reduced to

$$I_{C1} = \frac{V^+ - 3V_{BE} - \frac{R10}{R9} V^+}{R10 + R11 + R3} \quad (A. 2)$$

which shows that the collector current of Q1 is not affected by the common mode voltage.

The output voltage on the collector of Q2 is

$$V_{C2} = V^+ - I_{C2} R12 \quad (A. 3)$$

For zero differential input voltage, the collector currents of Q1 and Q2 will be equal so Equation (A. 3) becomes

$$V_{C2} = V^+ - \frac{R12 \left(V^+ - 3V_{BE} - \frac{R10}{R9} V^+ \right)}{R10 + R11 + R3} \quad (A. 4)$$

It is desired that this voltage be $3V_{BE}$ so that the output stage is just on the verge of switching with zero input. Forcing this condition and solving for R12 yields

$$R12 = (R10 + R11 + R3) \frac{V^+ - 3V_{BE}}{V^+ - 3V_{BE} - \frac{R10}{R9} V^+} \quad (A. 5)$$

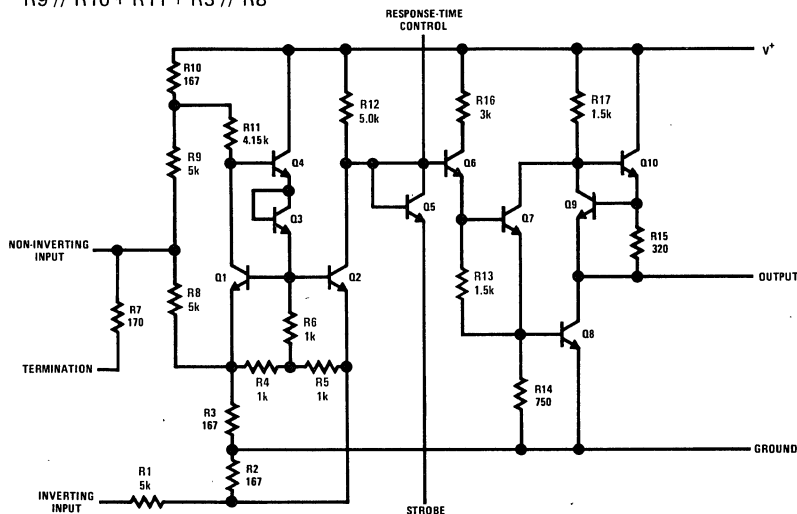


FIGURE A-1. Schematic Diagram of One Half of the DS7820 Line Receiver

This shows that the optimum value of R_{12} is dependent on supply voltage. For a 5V supply it has a value of 4.7 k Ω . Substituting this and the other component values into (A. 4),

$$V_{C2} = 2.83V_{BE} + 0.081V^+, \quad (\text{A. 6})$$

which shows that the voltage on the collector of Q2 will vary by about 80 mV for a 1V change in supply voltage.

The next step in the analysis is to obtain an expression for the voltage gain of the input stage.

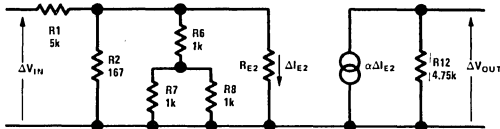


FIGURE A-2. Equivalent Circuit Used to Calculate Input Stage Gain

An equivalent circuit of the input stage is given in Figure A-2. Noting that $R_6 = R_7 = R_8$ and $R_2 \cong 0.1 (R_6 + R_7 // R_8)$, the change in the emitter current of Q1 for a change in input voltage is

$$\Delta I_{E2} = \frac{0.9 R_2}{R_1 (0.9 R_2 + R_{E2})} \Delta V_{IN}. \quad (\text{A. 7})$$

Hence, the change in output voltage will be

$$\begin{aligned} \Delta V_{OUT} &= \alpha I_{E2} R_{12} \\ &= \frac{0.9 \alpha R_2 R_{12}}{R_1 (0.9 R_2 + R_{E2})} \Delta V_{IN}. \end{aligned} \quad (\text{A. 8})$$

Since $\alpha \cong 1$, the voltage gain is

$$A_{V1} = \frac{0.9 R_2 R_{12}}{R_1 (0.9 R_2 + R_{E2})} \quad (\text{A. 9})$$

The emitter resistance of Q2 is given by

$$R_{E2} = \frac{kT}{qI_{C2}}, \quad (\text{A. 10})$$

$$\text{where } I_{C2} = \frac{V^+ - 3V_{BE}}{R_{12}} \quad (\text{A. 11})$$

$$\text{so } R_{E2} = \frac{kT R_{12}}{q (V^+ - 3V_{BE})} \quad (\text{A. 12})$$

Therefore, at 25°C where $V_{BE} = 670$ mV and $kT/q = 26$ mV, the computed value for gain is 0.745. The gain is not greatly affected by temperature as the gain at -55°C where $V_{BE} = 810$ mV and $kT/q = 18$ mV is 0.774, and the gain at 125°C where $V_{BE} = 480$ mV and $kT/q = 34$ mV is 0.730.

With a voltage gain of 0.75, the results of Equation (A. 6) show that the input referred threshold voltage will change by 0.11V for a 1V change in supply voltage. With the standard ± 10 -percent supplies used for logic circuits, this means that the threshold voltage will change by less than ± 60 mV.

Finally, the threshold error due to finite gain in the output stage can be considered. The collector current of Q7 from the bleeder resistor R_{14} , is large by comparison to the base current of Q8, if Q8 has a reasonable current gain. Hence, the collector current of Q7 does not change appreciably when the output switches from a logic one to a logic zero. This is even more true for Q6, an emitter follower which drives Q7. Therefore, it is safe to presume that Q6 does not load the output of the first-stage amplifier, because of the compounded current gain of the three transistors, and that Q8 is driven from a low resistance source.

It follows that the gain of the output stage can be determined from the change in the emitter-base voltage of Q8 required to swing the output from a logic one state to a logic zero state. The expression

$$\Delta V_{BE} = \frac{kT}{q} \log_e \frac{I_{C1}}{I_{C2}} \quad (\text{A. 13})$$

describes the change in emitter-base voltage required to vary the collector current from one value, I_{C1} , to a second, I_{C2} . With the output of the receiver in the low state, the collector current of Q8 is

$$\begin{aligned} I_{OL} &= \frac{V^+ - V_{OL} - V_{BE9} - V_{BE10}}{R_{17}} \\ &+ \frac{V_{BE9}}{R_{15}} - \frac{V_{BE8}}{R_{14}} + \frac{V_{BE7}}{R_{13}} + I_{SINK}, \end{aligned} \quad (\text{A. 14})$$

where V_{OL} is the low state output voltage and I_{SINK} is the current load from the logic that the receiver is driving. Noting that $R_{13} = 2R_{14}$ and figuring that all the emitter-base voltages are the same, this becomes

$$\begin{aligned} I_{OL} &= \frac{V^+ - V_{OL} - 2V_{BE} + V_{BE}}{R_{17}} + \frac{V_{BE}}{R_{15}} \\ &- \frac{V_{BE}}{2R_{14}} + I_{SINK}. \end{aligned} \quad (\text{A. 15})$$

Similarly, with the output in the high state, the collector current of Q8 is

$$\begin{aligned} I_{OH} &= \frac{V^+ - V_{OH} - V_{BE9} - V_{BE10}}{R_{17}} \\ &+ \frac{V_{BE9}}{R_{15}} - \frac{V_{BE8}}{R_{14}} \\ &+ \frac{V_{BE7}}{R_{13}} - I_{SOURCE}, \end{aligned} \quad (\text{A. 16})$$

where V_{OH} is the high-level output voltage and I_{SOURCE} is the current needed to supply the input leakage of the digital circuits loading the comparator.

With the same conditions used in arriving at (A. 15), this becomes

$$I_{OH} = \frac{V^+ - V_{OH} - 2V_{BE}}{R17} + \frac{V_{BE}}{R15} - \frac{V_{BE}}{2R14} - I_{SOURCE} \quad (\text{A. 17})$$

From (A. 13) the change in the emitter-base voltage of Q8 in going from the high output level to the low output level is

$$\Delta V_{BE} = \frac{kT}{q} \log_e \frac{I_{OL}}{I_{OH}} \quad (\text{A. 18})$$

providing that Q8 is not quite in saturation, although it may be on the verge of saturation.

The change of input threshold voltage is then

$$\Delta V_{TH} = \frac{kT}{qA_{V1}} \log_e \frac{I_{OL}}{I_{OH}} \quad (\text{A. 19})$$

where A_{V1} is the input stage gain. With a worst case fanout of 2, where $V_{OH} = 2.5V$, $V_{OL} = 0.4V$, $I_{SOURCE} = 40 \mu A$ and $I_{SINK} = 3.2 mA$, the calculated change in threshold is 37 mV at 25°C, 24 mV at -55°C and 52 mV at 125°C.

The measured values of overall gain differ by about a factor of two from the calculated gain. This is not too surprising because a number of assumptions were made which introduce small errors, and all these errors lower the gain. It is also not too important because the gain is high enough where another factor of two reduction would not cause the circuit to stop working.

The main contributors to this discrepancy are the non-ideal behavior of the emitter-base voltage of Q8 due to current crowding under the emitter and the variation in the emitter base voltage of Q7 and Q8 with changes in collector-emitter voltage (h_{RE}).

Although these parameters can vary considerably with different manufacturing methods, they are relatively fixed for a given process. The ΔV_{BE} errors introduced by these quantities, if known, can be added directly into Equation (A. 18) to give a more accurate gain expression.

The most stringent matching requirement in the receiver is the matching of the input stage divider resistors: R1 with R8 and R2 with R3. As little as 1% mismatch in one of these pairs can cause a threshold shift of 150 mV at the extremes of the $\pm 15V$ common mode range. Because of this, it is necessary to make the resistors absolutely identical and locate them close together. In addition, since R1 and R8 do dissipate a reasonable amount of power, they have to be located to minimize the thermal gradient between them. To do this, R9 was located between R1 and R8 so that it would heat both of these resistors equally. There are not serious heating problems with R2 and R3; however, because of their low resistance value, it was necessary even to match the lengths of the aluminum interconnects, as the resistance of the aluminum is high enough to cause intolerable mismatches. Of secondary importance is the matching of Q1 and Q2 and the matching of ratios between R11 and R12. A 1 mV difference in the emitter-base voltages of Q1 and Q2 causes a 30 mV input offset voltage as does a 1% mismatch in the ratio of R11 to R12.

The circuit is indeed insensitive to transistor current gains as long as they are above 10. The collector currents of Q4 and Q6 are made equal so that their base currents load the collectors of Q1 and Q2 equally. Hence, the input threshold voltage is affected only by how well the current gains match. Low current gain in the output transistor, Q8, can cause a reduction in gain. But even with a current gain of 10, the error produced in the input threshold voltage is less than 50 mV.



INTRODUCTION

Digital systems generally require the transmission of digital signals to and from other elements of the system. The component wavelengths of the digital signals will usually be shorter than the electrical length of the cable used to connect the subsystems together and, therefore, the cables should be treated as a transmission line. In addition, the digital signal is usually exposed to hostile electrical noise source which will require more noise immunity than required in the individual subsystems environment.

The requirements for transmission line techniques and noise immunity are recognized by the designers of subsystems and systems, but the solution used vary considerably. Two widely used example methods of the solution are shown in *Figure 1*. The two methods

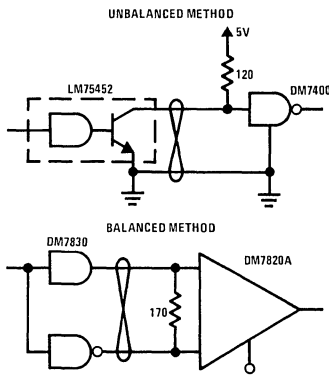


FIGURE 1.

illustrated use unbalanced and balanced circuit techniques. This application note will delineate the characteristics of digital signals in transmission lines and characteristics of the line that effect the quality, and will compare the unbalanced and balanced circuits performance in digital systems.

NOISE

The cables used to transmit digital signals external to a subsystem and in route between the subsystem, are exposed to external electromagnetic noise caused by

switching transients from actuating devices of neighboring control systems. Also external to a specific subsystem, another subsystem may have a ground problem which will induce noise on the system, as indicated in *Figure 2*.

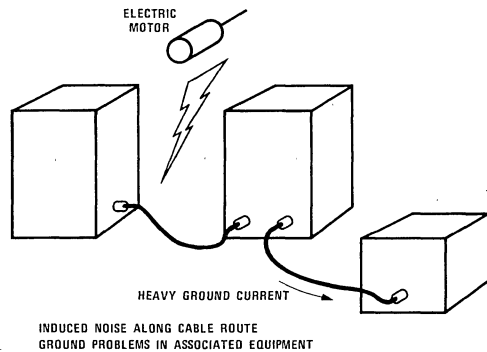


FIGURE 2. External Noise Sources

The signals in adjacent wires inside a cable may induce electromagnetic noise on other wires in the cable. The induced electromagnetic noise is worse when a line terminated at one end of the cable is near to a driver at the same end, as shown in *Figure 3*. Some noise may be

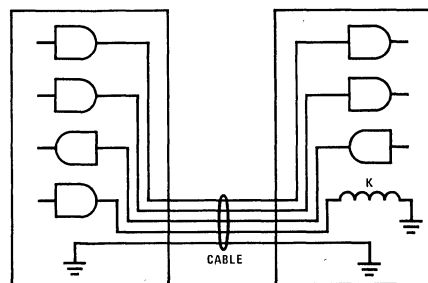


FIGURE 3. Internal Noise Sources

induced from relay circuits which have very large transient voltage swings compared to the digital signals in the same cable. Another source of induced noise is current in the common ground wire or wires in the cable.

DISTORTION

The objective is the transmission and recovery of digital intelligence between subsystems, and to this end, the characteristics of the data recovered must resemble the data transmitted. In *Figure 4* there is a difference in the pulse width of the data and timing signal transmitted, and the corresponding signal received. In addition there is a further difference in the signal when the data is "AND"ed with the timing signal. The distortion of the signal occurred in the transmission line and in the line driver and receiver.

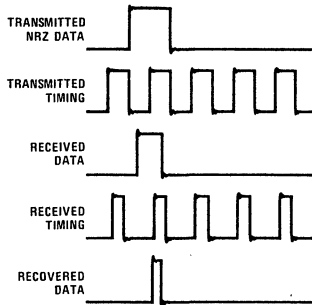


FIGURE 4. Effect of Distortion

A primary cause of distortion is the effect the transmission line has on the rise time of the transmitted data. *Figure 5* shows what happens to a voltage step from the driver as it travels down the line. The rise time of the signal increases as the signal travels down the line. This effect will tend to affect the timing of the recovered signal.

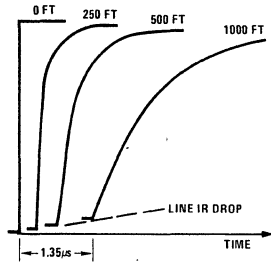


FIGURE 5. Signal Response at Receiver

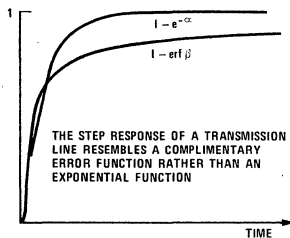


FIGURE 6. Signal Rise Time

The rise time in a transmission line is not an exponential function but a complementary error function. The high frequency components of the step input are attenuated and delayed more than the low frequency components. This attenuation is inversely proportional to the frequency. Notice in *Figure 6* particularly that the signal takes much longer to reach its final dc value. This effect is more significant for fast risetimes.

The Duty Cycle of the transmitted signal also causes distortion. The effect is related to the signal rise time as shown in *Figure 7*. The signal doesn't reach one logic level before the signal changes to another level. If the signal has a 1/2 (50%) Duty Cycle and the threshold of the receiver is halfway between the logic levels, the distortion is small. But if the Duty Cycle is 1/8 as shown in the second case the signal is considerably distorted. In some cases, the signal may not reach the receiver threshold at all.

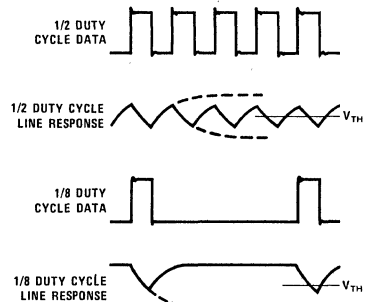


FIGURE 7. Signal Distortion Due to Duty Cycle

In the previous example, it was assumed that the threshold of the receiver was halfway between the ONE and ZERO logic levels. If the receiver threshold isn't halfway the receiver will contribute to the distortion of the recovered signal. As shown in *Figure 8*, the pulse time is lengthened or shortened, depending on the polarity of the signal at the receiver. This is due to the offset of the receiver threshold.

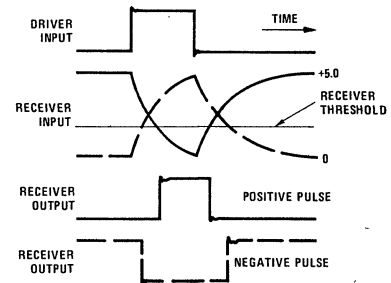


FIGURE 8. Slicing Level Distortion

UNBALANCED METHOD

Another source of distortion is caused by the IR losses in the wire. *Figure 9* shows the IR losses that occur in a thousand feet of no. 22 AWG wire. Notice in this

example that the losses reduce the signal below the threshold of the receiver in the unbalanced method. Also that part of the IR drop in the ground wire is common to other circuits—this ground signal will appear as a source of noise to the other unbalanced line receivers in the system.

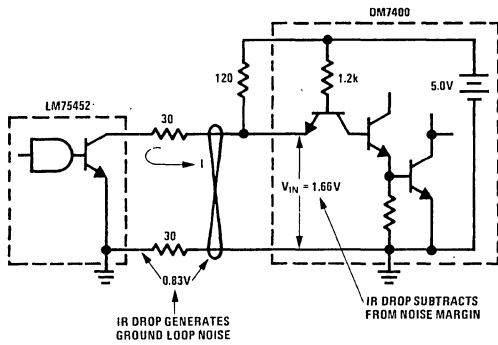


FIGURE 9. Unbalanced Method

Transmission lines don't necessarily have to be perfectly terminated at both ends, (as will be shown later) but the termination used in the unbalanced method will cause additional distortion. Figure 10 shows the signal on the transmission line at the driver and at the receiver. In this case the receiver was terminated in 120Ω, but the characteristic impedance of the line is much less. Notice that the wave forms have significant steps due to the incorrect termination of the line. The signal is subject to misinterpretation by the line receiver during the period of this signal transient because of the distortion caused by Duty Cycle and attenuation. In addition, the noise margin of the signal is reduced.

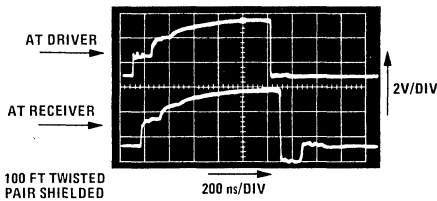


FIGURE 10. LM75451, DM7400 Line Voltage Waveforms

The signal waveforms on the transmission line can be estimated before hand by a reflection diagram. Figure 11 shows the reflection diagram of the rise time wave forms. The voltage versus current plot on left is used to predict the transient rise time of the signal shown on the right. The initial condition on the transmission line is an IR drop across the line termination. The first transient on the line traverses from this initial point to zero current. The path it follows corresponds to the characteristic impedance of the line. The second transient on the diagram is at the line termination. As shown, the signal reflects back and forth until it reaches its final dc value.

Figure 12 shows the reflection diagram of the fall time. Again the signal reflects back and forth between the line

termination until it reaches its final dc value. In both the rise and fall time diagrams, there are transient voltage and current signals that subtract from the particular signal and add to the system noise.

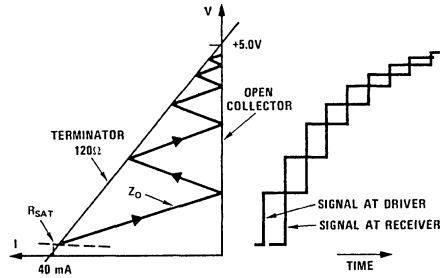


FIGURE 11. Line Reflection Diagram of Rise Time

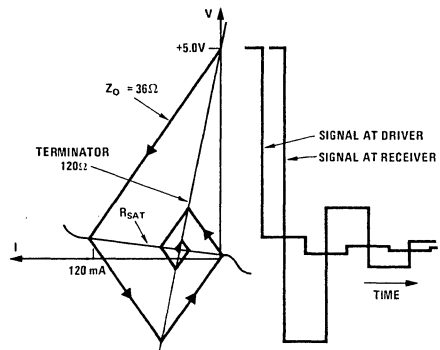
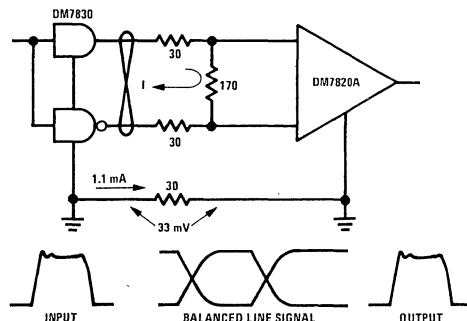


FIGURE 12. Line Reflection Diagram of Fall Time

BALANCED METHOD

In the balanced method shown in Figure 13, the transient voltages and currents on the line are equal and



THE GROUND LOOP CURRENT IS MUCH LESS THAN SIGNAL CURRENT

FIGURE 13. Cross Talk of Signals

opposite and cancel each others noise. Also unlike the unbalanced method, they generate very little ground noise. As a result, the balanced circuit doesn't contribute to the noise pollution of its environment.

The circuit used for a line receiver in the balanced method is a differential amplifier. Figure 14 shows a noise transient induced equally on line A and line B from line C. Because the signals on line A and B are equal, the signals are ignored by the differential line receiver.

Likewise for the same reason, the differential signals on line A and B from the driver will not induce transients on line C. Thus, the balanced method doesn't generate noise and also isn't susceptible to noise. On the other hand the unbalanced method is more sensitive to noise and also generates more noise.

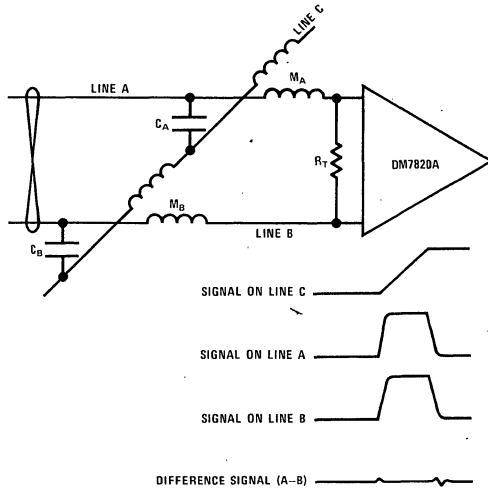


FIGURE 14. Cross Talk of Signals

The characteristic impedance of the unbalanced transmission line is less than the impedance of the balanced transmission line. In the unbalanced method there is more capacitance and less inductance than in the balanced method. In the balance method the Reactance to adjacent wires is almost cancelled (see Figure 15). As a result a transmission line may have a 60Ω unbalanced impedance and a 90Ω balanced impedance. This means that the unbalanced method, which is more susceptible to IR drop, must use a smaller value termination, which will further increase the IR drop in the line.

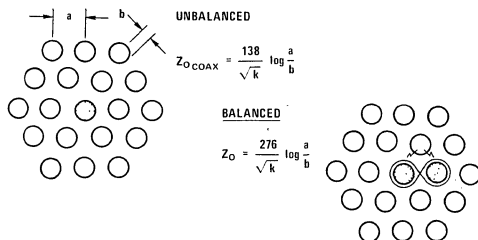


FIGURE 15. Z_0 Unbalanced < Z_0 Balanced

The impedance measurement of an unbalance and balance line must be made differently. The balanced impedance must be measured with a balanced signal. If there is any unbalance in the signal on the balanced line, there will be

an unbalance reflection at the terminator. Therefore, the lines should also be terminated for unbalanced signals. Figure 16 shows the perfect termination configuration of a balanced transmission line. This termination method is primarily required for accurate impedance measurements.

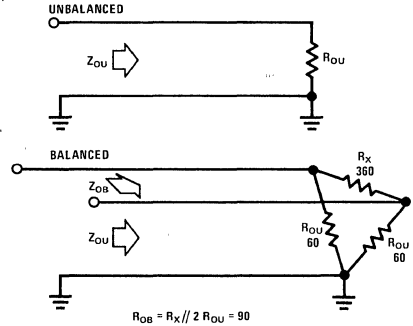


FIGURE 16. Impedance Measurement

MEASURED PERFORMANCE

The unbalanced method circuit used in this application note up to this point is the unbalanced circuit shown in Figure 1. The termination of its transmission line was greater than the characteristic impedance of the unbalanced line and the circuit had considerable threshold offset. The measured performance of the unbalanced circuit wasn't comparable to the balanced method. Therefore, for the following comparison of unbalanced and balanced circuits, an improved termination shown in Figure 17 will be used. This circuit terminates the line in 60Ω and minimized the receiver threshold offset.

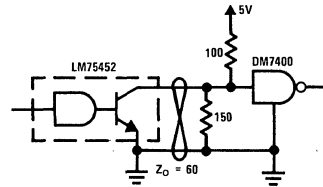


FIGURE 17. Improved Unbalanced Method

A plot of the Absolute Maximum Data Rate versus cable type is shown in Figure 18. The graph shows the different performances of the DM7820A line receiver and

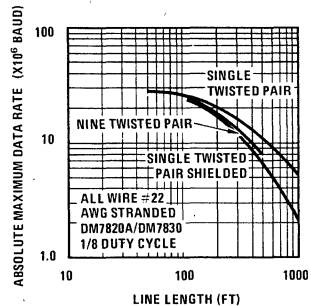


FIGURE 18. Data Rate vs Cable Type

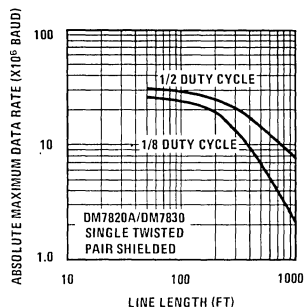


FIGURE 19. Data Rate vs Duty Cycle

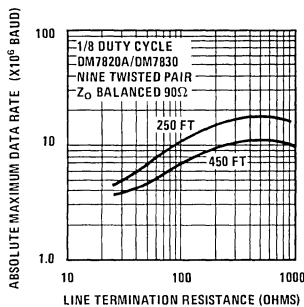


FIGURE 20. Data Rate vs Line Termination

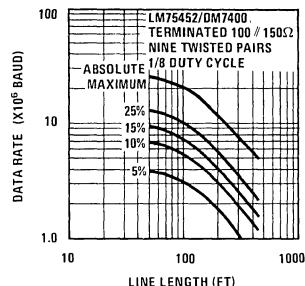


FIGURE 21. Data Rate vs Distortion of LM75452, DM7400

the DM7830 line driver circuits with a worse case 1/8 Duty Cycle in no. 22 AWG stranded wire cables. In a single twisted pair cable there is less reactance than in a cable having nine twisted pairs and in turn this cable has less reactance than shielded pairs. The line length is reduced in proportion to the increased line attenuation which is proportional to the line reactance. The plot shows that the reactance and attenuation has a significant effect on the cable length. Absolute Maximum Data Rate is defined as the Data Rate at which the output of the line receiver is starting to be degraded. The roll off of the performance above 20 mega baud is due to the circuit switching response limitation.

Figure 19 shows the reduction in Data Rate caused by Duty Cycle. It can be observed that the Absolute Maximum Duty Rate of 1/8 Duty Cycle is less than 1/2 Duty Cycle. The following performance curves will use 1/8 Duty Cycle since it is the worst case.

Absolute Maximum Duty Rate versus the Line Termination Resistance for two different lengths of cable is shown in Figure 20. It can be seen from the figure that the termination doesn't have to be perfect in the case of balanced circuits. It is better to have a termination resistor to minimize the extra transient signal reflecting between the ends of the line. The reason the Data Rate increases with increased Termination Resistance is that there is less IR drop in the cable.

The graphs in Figure 21 shows the Data Rate versus the Line Length for various percentage of timing distortion using the unbalanced LM75452 and DM7400 circuits shown in Figure 17. The definition of Timing Distortion

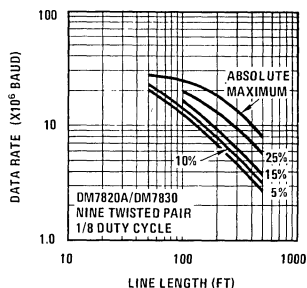


FIGURE 22. Data Rate vs Distortion of DM7820A, DM7830

is the percentage difference in the pulse width of the data sent versus the data received.

Data Rate versus the Line Length for various percentage of timing distortion using the balanced DM7820A and DM7830 circuit is shown in Figure 22. The distortion of this method is improved over the unbalanced method, as was previously theorized.

The Absolute Maximum Data Rate versus Line Lengths shown in the previous two figures didn't include any induced signal noise. Figure 23 shows the test configuration of the unbalanced circuits which was used to

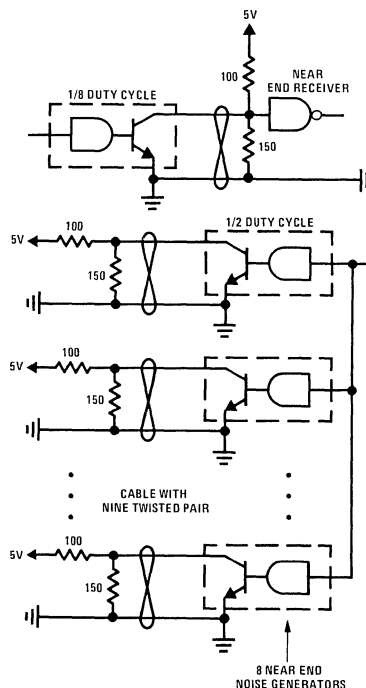


FIGURE 23. Signal Cross Talk Experiment Using DM75452, DM7400

measure near end cross talk noise. In this configuration there are eight line drivers and one receiver at one end of the cable. The performance of the receiver measured in the presence of the driver noise is shown in Figure 24.

Figure 24 shows the Absolute Maximum Duty Rate of the unbalanced method versus line length and versus the number of line drivers corresponding to the test configuration delineated in Figure 23. In the noise measurement set-up there was a ground return for each signal wire. If there is only one ground return in the cable the performance is worse. The graph shows that the effective line length is drastically reduced as additional Near End Drivers are added. When this performance is compounded by timing distortion the performance is further reduced.

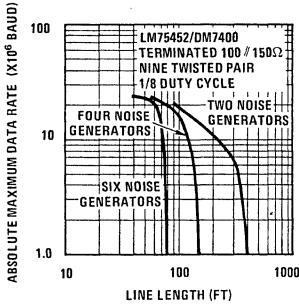


FIGURE 24. Data Rate vs Signal Cross Talk of LM75452, DM7400

Figure 25 shows the test configuration of the balanced circuit used to generate worst case Near End cross talk

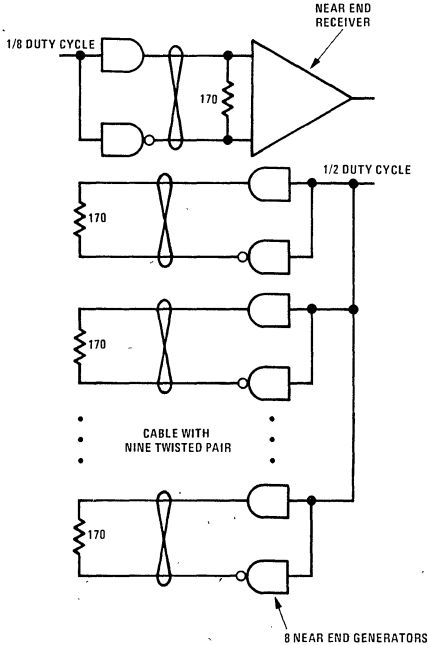


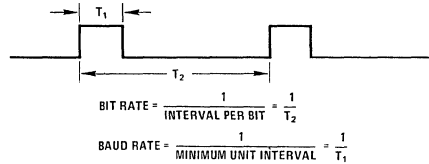
FIGURE 25. Signal Cross Talk Experiment Using DM7830, DM7820A

noise similar to the unbalance performance shown in the previous figure. Unlike the unbalanced case, there was no measurable degradation of the circuits Data Rate or distortion.

CONCLUSION

National has a full line of both Balanced and Unbalanced Line Drivers and Receivers. Both circuit types work well when used within their limitations. This application note shows that the balanced method is preferable for long lines in noisy electrical environments. On the other hand the unbalanced circuit works perfectly well with shorter lines and reduced data rates. It should be kept in mind that when you are spending \$500,000 for a CPU and \$75,000 for peripherals, it pays to investigate the best way to transmit data between them.

DEFINITION OF BAUD RATE



The data in this note was plotted versus Baud Rate. The minimum unit interval reflected the worse case conditions and also normalized the diagrams so that the diagrams were independent of duty cycle. If the duty cycle is 50% then the Baud Rate is twice the Bit Rate.

REFERENCES

IC's for Digital Data Transmission, Widlar and Kubinec, *National Semiconductor Application Note AN-22.*

Data Bus and Differential Line Drivers and Receivers, Richard Percival, *National Semiconductor Application Note AN-83.*

RADC TR73-309, Experimental Analysis of the Transmission of Digital Signals over Twisted Pair Cable, Hendrickson and Evanowski, *Digital Communication Section Communications and Navigation Division, Rome Air Development Center, Griffis Air Force Base, New York.*

Fast Pulse Techniques, Thad Dreher, E-H Research Laboratories, Inc., *The Electronic Engineer*, Aug. 1969.

Transient Analysis of Coaxial Cables, Considering Skin Effects, Wigington and Nahmaj, *Proceedings of the IRE*, Feb. 1957.

Reflection and Crosstalk in Logic, Circuit Interconnections, John DeFalco, Honeywell, Inc., *IEEE Spectrum*, July 1970.

Transmission Line Drivers and Receivers for EIA Standards RS-422 and RS-423

National Semiconductor
Application Note 214
John Abbott
October 1978



AN-214

With the advent of the microprocessor, logic designs have become both sophisticated and modular in concept. Frequently the modules making up the system are very closely coupled on a single printed circuit board or cardfile. In a majority of these cases a standard bus transceiver will be adequate. However because of the distributed intelligence ability of the microprocessor, it is becoming common practice for the peripheral circuits to be physically separated from the host processor with data communications being handled over cables (e.g. plant environmental control or security system). And often these cables are measured in hundreds or thousands of feet as opposed to inches on a backplane. At this point the component wavelengths of the digital signals may become shorter than the electrical length of the cable and consequently must be treated as transmission lines. Further, these signals are exposed to electrical noise sources which may require greater noise immunity than the single chassis system.

It is the object of this application note to underscore the more important design requirements for balanced and unbalanced transmission lines, and to show that National's DS1691 driver and DS78LS120 receiver meet or exceed all of those requirements.

THE REQUIREMENTS

The requirements for transmission lines and noise immunity have been adequately recognized by National

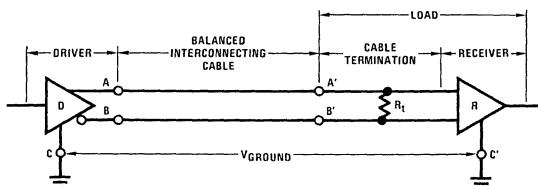
Semiconductor's application note AN-108 and E.I.A. standards RS-422 (balanced) and RS-423 (unbalanced). A summary review of these notes will show that the controlling factors in a voltage digital interface are:

- 1) The cable length
- 2) The modulation rate
- 3) The characteristic of the interconnection cable
- 4) The rise time of the signal

RS-422 and RS-423 contain several useful guidelines relative to the choice of balanced circuits versus unbalanced circuits. *Figures 1a and 1b* are the digital interface for balanced (*1a*) and unbalanced (*1b*) circuits.

Even though the unbalanced interface circuit is intended for use at lower modulation rates than the balanced circuit, its use is not recommended where the following conditions exist:

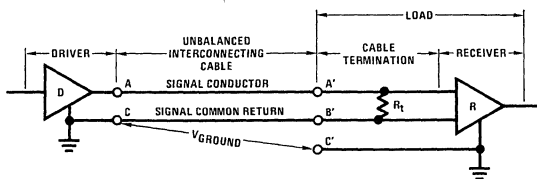
- 1) The interconnecting cable is exposed to noise sources which may cause a voltage sufficient to indicate a change of binary state at the load.
- 2) It is necessary to minimize interference with other signals, such as data versus clock.
- 3) The interconnecting cable is too long electrically for unbalanced operation (*Figure 2*)



Legend:

R_t = Optional cable termination resistance/receiver input impedance. A', B' = Load interface
 V_{GROUND} = Ground potential difference C = Driver circuit ground
 A, B = Driver interface C' = Load circuit ground

FIGURE 1a. RS-422 Balanced Digital Interface Circuit



Legend:

R_t = Transmission line termination and/or receiver input impedance A', B' = Load interface
 V_{GROUND} = Ground potential difference C = Driver circuit ground
 A, C = Driver interface C' = Load circuit ground

FIGURE 1b. RS-423 Unbalanced Digital Interface Circuit

1

CABLE LENGTH

While there is no maximum cable length specified, guidelines are given with respect to conservative operating distances as a function of modulation rate. Figure 2 is a composite of the guidelines provided by RS-422 and RS-423 for data modulation versus cable length. The data is for 24 AWG twisted pair cable terminated for worst case (due to IR drop) in a 100 Ohm load, with rise and fall times equal to or less than one half unit interval at the applied modulation rate.

The maximum cable length between driver and load is a function of the baud rate. But it is influenced by:

- 1) A maximum common noise range of ± 7 volts
 - A) The amount of common-mode noise
Difference of driver and receiver ground potential plus driver offset voltage and coupled peak random noise.
 - B) Ground potential differences between driver and load.
 - C) Cable balance
Differential noise caused by imbalance between the signal conductor and the common return (ground)
- 2) Cable termination
At rates above 200 kilobaud or where the rise time is 4 times the one way propagation delay time of the cable (RS-422 Sec 7.1.2)
- 3) Tolerable signal distortion

MODULATION RATE

Section 3 of RS-422 and RS-423 states that the unbalanced voltage interface will normally be utilized on data, timing or control circuits where the modulation rate on these circuits is below 100 kilobauds, and balanced voltage digital interface on circuits up to 10 megabauds. The voltage digital interface devices meeting the electrical characteristics of this standard need not meet the entire modulation range specified. They may be designed to operate over narrower ranges to more economically satisfy specific applications, particularly at the lower modulation rates.

As pointed out in AN-108, the duty cycle of the transmitted signal contributes to the distortion. The effect is the result of rise time. Due to delay and attenuation caused by the cable, it is possible due to AC averaging of the signal, to be unable to reach one binary level before it is changed to another. If the duty cycle is 1/2 (50%) and the receiver threshold is midway between logic levels, the distortion is small. However if the duty cycle were 1/8 (12.5%) the signal would be considerably distorted.

CHARACTERISTICS

Driver Unbalanced (RS-423)

The unbalanced driver characteristics as specified by RS-423 Sec 4.1 are as follows:

- 1) A driver circuit should be a low impedance (50 Ohms or less) unbalanced voltage source that will produce a voltage applied to the interconnecting cable in the range of 4 volts to 6 volts.
- 2) With a test load of 450 Ohms connected between the driver output terminal and the driver circuit ground, the magnitude of the voltage (VT) measured between the driver output and the driver circuit ground shall not be less than 90% of the magnitude for either binary state.
- 3) During transitions of the driver output between alternating binary states, the signal measured across a 450 Ohm test load connected between the driver output and circuit ground should be such that the voltage monotonically changes between 0.1 and 0.9 of V_{SS} . Thereafter, the signal shall not vary more than 10% of V_{SS} from the steady state value, until the next binary transition occurs, and at no time shall the instantaneous magnitude of V_T and $\overline{V_T}$ exceed 6 volts, nor be less than 4 volts. V_{SS} is defined as the voltage difference between the 2 steady state values of the driver output.

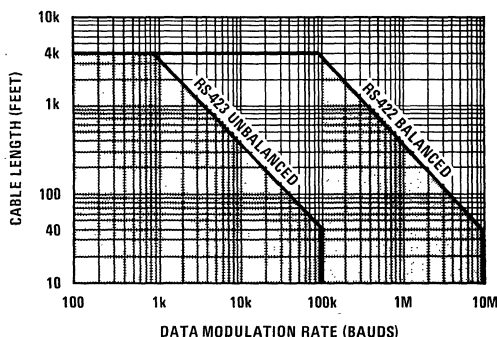
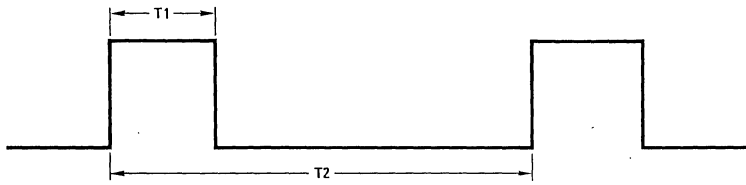


FIGURE 2. Data Modulation Rate vs Cable Length



$$\text{Bit Rate} = \frac{1}{\text{Interval Per Bit}} = \frac{1}{T_2}$$

$$\text{Baud Rate} = \frac{1}{\text{Minimum Unit Interval}} = \frac{1}{T_1}$$

FIGURE 3a. Definition of Baud Rate

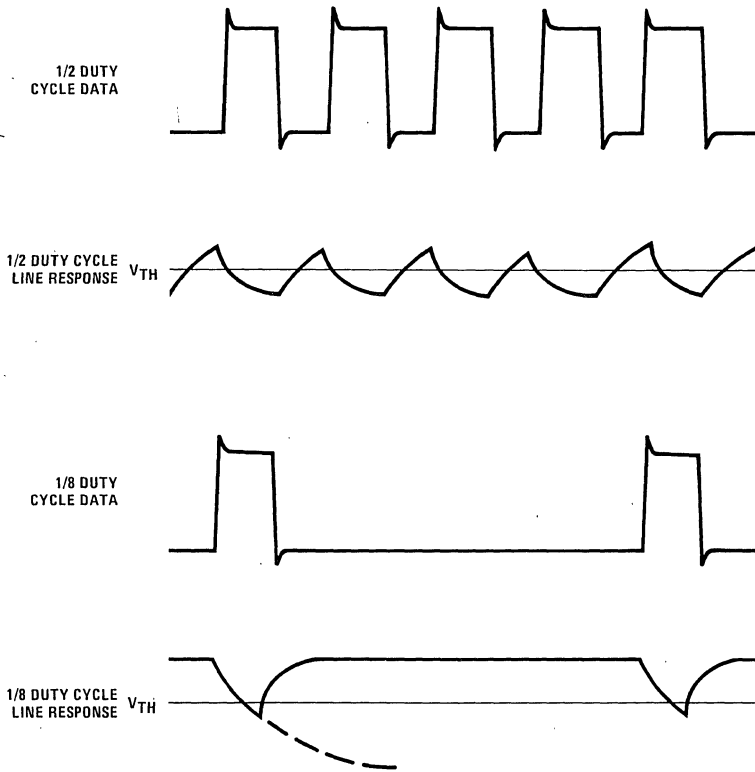


FIGURE 3b. Signal Distortion Due to Duty Cycle

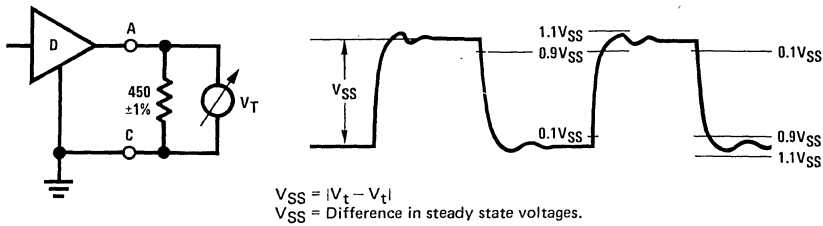


FIGURE 4. Unbalanced Driver Output Signal Waveform

Driver Balanced (RS-422)

The balanced driver characteristics as specified by RS-422 Sec 4.1 are as follows:

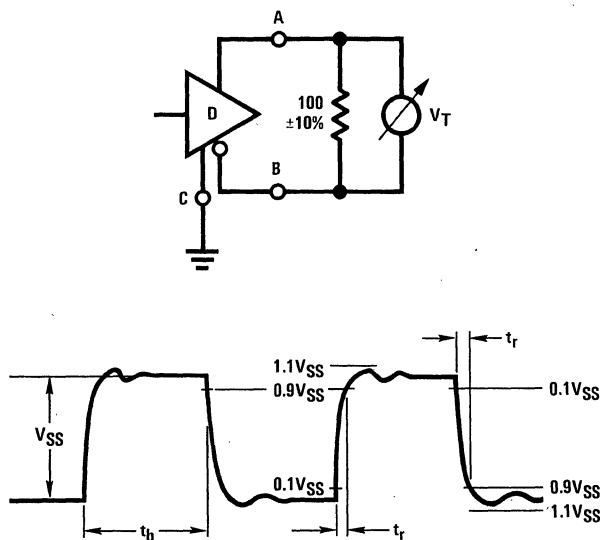
- 1) A driver circuit should result in a low impedance (100 Ohms or less) balanced voltage source that will produce a differential voltage applied to the interconnecting cable in the range of 2 volts to 6 volts.
- 2) With a test load of 2 resistors, 50 Ohms each, connected in series between the driver output terminals, the magnitude of the differential voltage (V_T) measured between the 2 output terminals shall not be less than either 2.0 volts or 50% of the magnitude of V_O , whichever is greater. For the opposite binary state the polarity of V_T shall be reversed ($\overline{V_T}$). The magnitude of the difference in the magnitude of V_T and $\overline{V_T}$ shall be less than 0.4 volts. The magnitude of the driver offset voltage (V_{OS}) measured between the center point of the test load and driver circuit ground shall not be greater than 3.0 volts. The magnitude of the difference in the magnitude of V_{OS} for one binary state and $\overline{V_{OS}}$ for the opposing binary state shall be less than 0.4 volts.
- 3) During transitions of the driver output between alternating binary states, the differential signal measured across a 100 Ohm test load connected between the driver output terminals shall be

such that the voltage monotonically changes between 0.1 and 0.9 of V_{SS} within 0.1 of the unit interval or 20 nanoseconds, whichever is greater. Thereafter the signal voltage shall not vary more than 10% of V_{SS} from the steady state value, until the next binary transition occurs, and at no time shall the instantaneous magnitude of V_T or $\overline{V_T}$ exceed 6 volts, nor less than 2 volts.

Interconnecting Cable

The characteristics of the interconnecting cable should result in a transmission line with a characteristic impedance in the general range of 100 Ohms to frequencies greater than 100 kilohertz, and a DC series loop resistance not exceeding 240 Ohms. The cable may be composed of twisted or untwisted pair (flat cable) possessing the characteristics specified in RS-422 Sec 4.3 as follows:

- 1) Conductor size of the 2 wires shall be 24 AWG or larger with wire resistance not to exceed 30 Ohms per 1000 feet per conductor
- 2) Mutual pair capacitance between 1 wire in the pair to the other shall not exceed 20 pF per foot.
- 3) Stray capacitance between 1 wire in the pair with all other wires connected to ground, shall not exceed 40 pF per foot.



t_b = Time duration of the unit interval at the applicable modulation rate.

$t_r \leq 0.1 t_b$ when $t_b \geq 200$ ns

$t_r \leq 20$ ns when $t_b < 200$ ns

V_{SS} = Difference in steady state voltages

$V_{SS} = |V_t - \overline{V_t}|$

FIGURE 5. Balanced Driver Output Signal Waveform

Receiver

The load characteristics are identical for both balanced (RS-422) and unbalanced (RS-423) circuits. Each consists of a receiver and optional termination resistance as shown in *Figure 1*. The electrical characteristics single receiver without termination or optional fail-safe provisions are specified in RS-422/423 Sec 4.2 as follows:

- 1) Over an entire common-mode voltage range of -7 to $+7$ volts, the receiver shall not require a differential input voltage or more than 200 millivolts to correctly assume the intended binary state. The common-mode voltage (V_{CM}) is defined as the algebraic mean of the 2 voltages appearing at the receiver input terminals with respect to the receiver circuit ground. Reversing the polarity of V_T shall cause the receiver to assume the opposite binary state. This allows for operations where there are ground differences caused by IR drop and noise of up to ± 7 volts.
- 2) To maintain correct operation for differential input signal voltages ranging between 200 millivolts and 6 volts in magnitude.
- 3) The maximum voltage present between either receiver input terminal and receiver circuit ground shall not exceed 10 volts (3 volt signal plus 7 volts common-mode) in magnitude nor cause the receiver to operationally fail. Additionally, the receiver shall tolerate a maximum differential signal of 12 volts applied across its input terminals without being damaged.
- 4) The total load including up to 10 receivers shall not have a resistance greater than 90 Ohms for balanced, and 400 Ohms unbalanced at its input points and shall not require a differential input voltage of greater than 200 millivolts for all receivers to assume the correct binary state.

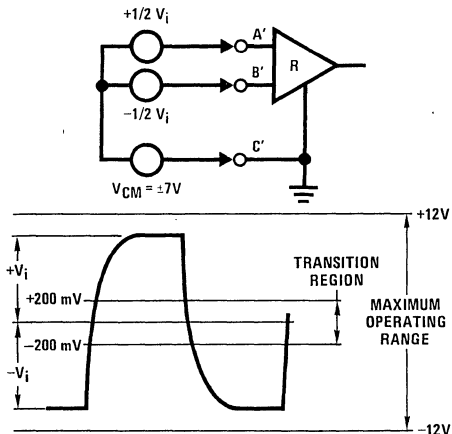


FIGURE 6. Receiver Input Sensitivity Measurement

Note: Designers of terminating hardware should be aware that slow signal transitions with superimposed noise present may give rise to instability or oscillations in the receiving device, and therefore appropriate techniques should be implemented to prevent such behavior. For example, adequate hysteresis and response control may be incorporated into the receiver to prevent such conditions.

- 5) Fail-safe operation per RS-423 Sec 4.2.5 states that other standards and specifications using the electrical characteristics of the unbalanced interface circuit may require that specific interchange leads be made fail-safe to certain fault conditions. Where fail-safe operation is required by such referencing standards and specifications, a provision shall be incorporated in the load to provide a steady binary condition (either "1" or "0") to protect against certain fault conditions (open or shorted cable).

The designer should be aware that in circuits employing pull-up resistors, the resistors used become part of the termination.

SIGNAL RISE TIME

The signal rise time is a high frequency component which causes interference (near end cross-talk) to be coupled to adjacent channels in the interconnecting cable. The near-end crosstalk is a function of both rise time and cable length, and in considering wave shaping, both should be considered. Since in the balanced voltage digital interface the output is complementary, there is practically no cross-talk coupled and therefore wave shaping is limited to unbalanced circuits.

Per RS-423 Sec 4.1.6, the rise time of the signal should be controlled so that the signal has reached 90% of V_{SS} between 10% and 30% of the unit interval at the maximum modulation rate. Below 1 kilobaud the time to reach 90% V_{SS} shall be between 100 and 300 microseconds. If a driver is to operate over a range of modulation rates and employ a fixed amount of wave shaping which meets the specification for the maximum modulation rate of the operating range, the wave shaping is considered adequate for all lesser modulation rates.

However a major cause of distortion is the effect the transmission line has on the rise time of the transmitted signal. *Figure 7* shows the effect of line attenuation and delay to a voltage step as it progresses down the cable. The increase of the rise time with distance will have a considerable effect on the distortion at the receiver. Therefore in fixing the amount of wave shaping employed, caution should be taken not to use more than the minimum required.

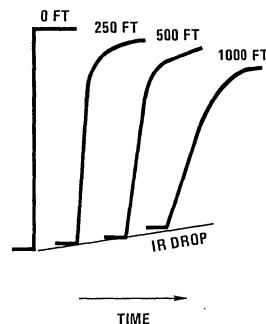


FIGURE 7. Signal Rise Time on Transmission Line vs Line Length

DS1691, DS78LS120

The Driver

The DS1691/DS3691 are low power Schottky TTL line drivers designed to meet the above listed requirements of EIA standard RS-422 and RS-423. They feature 4 buffered outputs with high source and sink current capability with internal short circuit protection. The DS1691/DS3691 employ a mode selection pin which allows the circuit to become either a pair of balanced drivers (Figure 8) or 4 independent unbalanced drivers (Figure 9). When configured for unbalanced operation (Figure 10) a rise time control pin allows the use of an external capacitor to control rise time for suppression of near end cross-talk to adjacent channels in the interconnect cable. Figure 11 is the typical rise time vs external capacitor used for wave shaping.

The DS3691 configured for RS-422 is connected $V_{CC} = 5V$ $V_{EE} = 0V$; and configured for RS-423 connected $V_{CC} = 5V$ $V_{EE} = -5V$. For applications outside RS-422 conditions and for greater cable lengths the DS1691/DS3691 may be connected with a V_{CC} of 5 volts and V_{EE} of -5 volts. This will create an output which is symmetrical about ground, similar to Mil Standard 188-114.

When configured as balanced drivers (Figure 8), each of the drivers is equipped with an independent TRI-STATE® control pin. By use of this pin it is possible to force the driver into its high impedance mode for applications using party line techniques.

If the common-mode voltage, between driver 1 and all other drivers in the circuit, is small then several line drivers (and receivers) may be incorporated into the system. However, if the common-mode voltage exceeds the TRI-STATE common-mode range of any driver, then the signal will become attenuated by that driver to the extent the common-mode voltage exceeds its common-mode range (See Figure 12, top waveform).

It is important then to select a driver with a common-mode range equal to or larger than the common-mode voltage requirement of the system. In the case of RS-422 and RS-423 the minimum common-mode range would be ± 7 volts. The DS1692/DS3692 driver is tested to a common-mode range of ± 10 volts and will operate within the requirements of such a system (See Figure 12, bottom waveform).

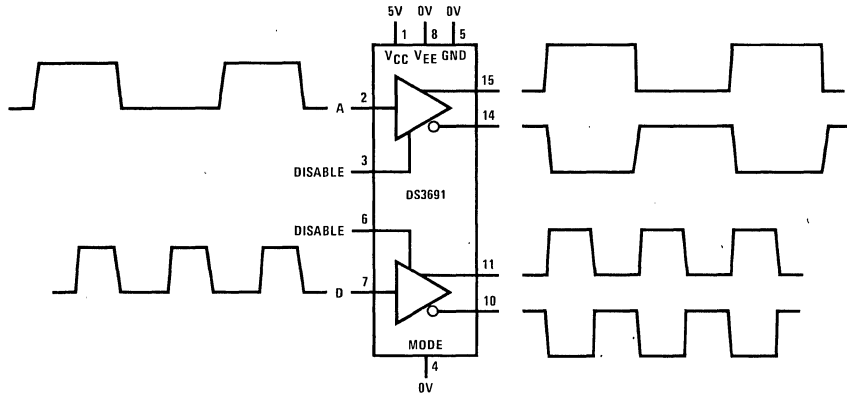


FIGURE 8. DS3691 Connected for Balanced Mode Operation

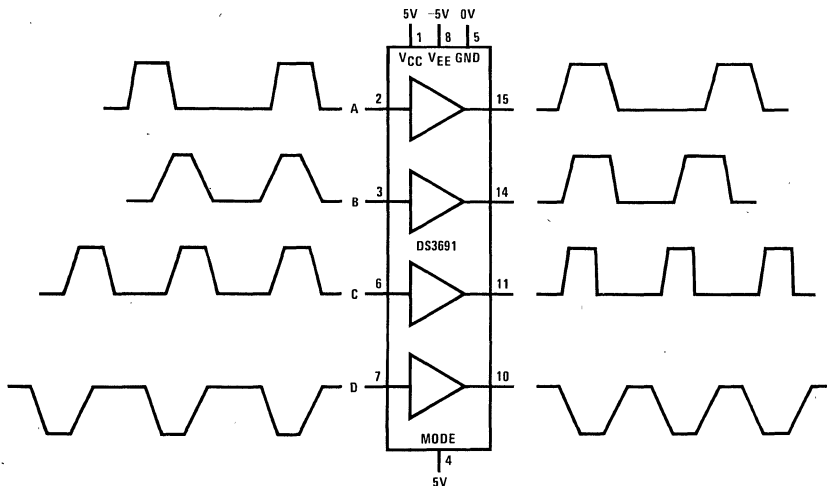


FIGURE 9. DS3691 Connected for Unbalanced Mode Operation

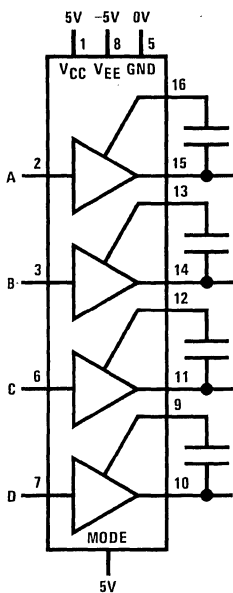


FIGURE 10. Using an External Capacitor to Control Rise Time of DS3691

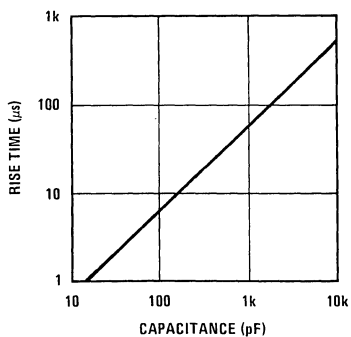


FIGURE 11. DS3691 Rise Time vs External Capacitor

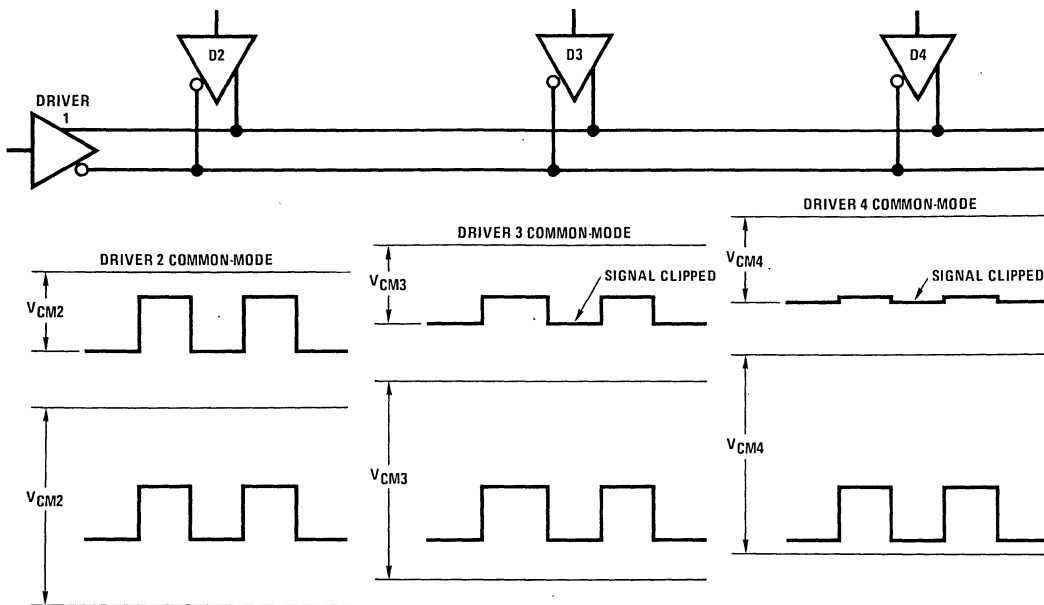


FIGURE 12. Comparison of Drivers without TRI-STATE Common-mode Output Range (Top Waveforms) to DS3691 (Bottom Waveforms)

DS78LS120/DS88LS120
The Receiver

The DS78LS120/DS88LS120 are high performance, dual differential, TTL compatible line receivers which meet or exceed the above listed requirements for both balanced and unbalanced voltage digital interface.

The line receiver will discriminate a ± 200 millivolt input signal over a full common-mode range of ± 10 volts and a ± 300 millivolt signal over a full common-mode range of ± 15 volts.

The DS78LS120/DS88LS120 include response control for applications where controlled rise and fall times and/or high frequency noise rejection are desirable. Switching noise which may occur on the input signal

can be eliminated by the 50 mV (referred to input) of hysteresis built into the output gate (Figure 14). The DS78LS120/DS88LS120 makes use of a response control pin for the addition of an external capacitor, which will not effect the line termination impedance of the interconnect cable. Noise pulse width rejection versus the value of the response control capacitor is shown in Figure 15. The combination of the filter followed by hysteresis will optimize performance in a worse case noise environment. The DS78C120/DS88C120 is identical in performance to the DS78LS120/DS88LS120, except it's compatible with CMOS logic gates.

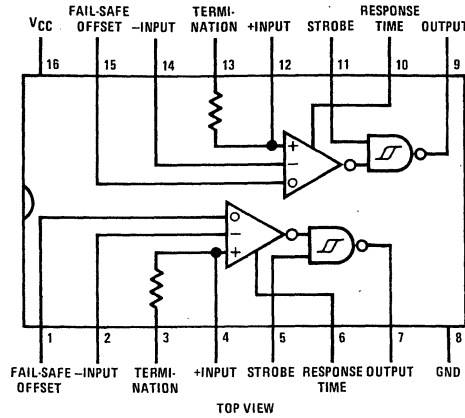


FIGURE 13. DS78LS120/DS88LS120 Dual Differential Line Receiver

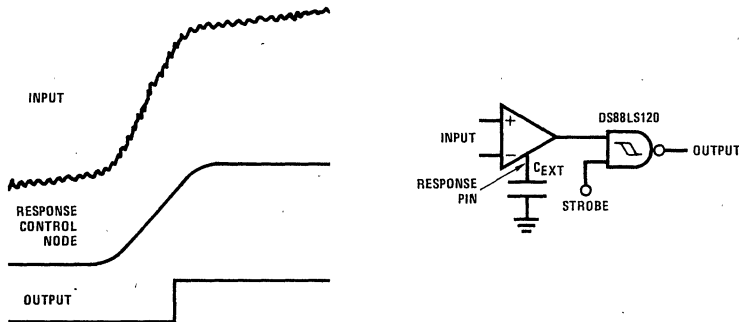


FIGURE 14. Application of DS88LS120 Receiver Response Control and Hysteresis

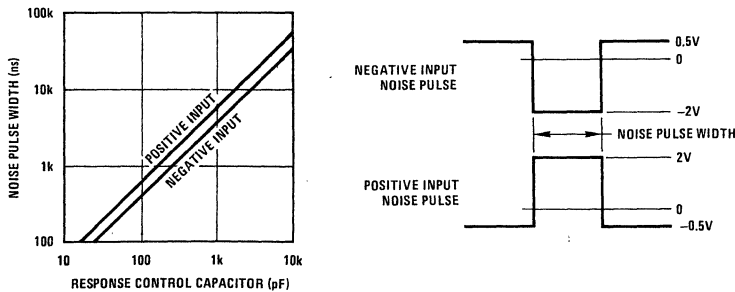


FIGURE 15. Noise Pulse Width vs Response Control Capacitor

FAIL-SAFE OPERATION

Communication systems require elements of a system to detect the loss of signals in the transmission lines. And it is desirable to have the system shut-down in a fail-safe mode if the transmission line is open or short. To facilitate the detection of input opens or shorts, the DS78LS120/DS88LS120 incorporates an input threshold voltage offset. This feature will force the line receiver to a specific logic state if presence of either fault condition exists.

The receiver input threshold is ± 200 millivolts and an input signal greater than ± 200 millivolts insures the receiver will be in a specific logic state. When the offset control input is connected to a $V_{CC} = 5$ volts, the input thresholds are offset from 200 to 700 millivolts, referred to the non-inverting input, or -200 to -700 millivolts, referred to the inverting input. Therefore, if the input is open or short, the input will remain in a specific state (See Figure 16).

It is recommended that the receiver be terminated in 500 Ohms or less to insure it will detect an open circuit in the presence of noise.

For unbalanced operation, the receiver would be in an indeterminate logic state if the offset control input was open. Connecting the offset to $+5$ volts, offsets the receiver threshold 0.45 volts. The output is forced to a logic zero state if the input is open or short.

For balanced operation with inputs short or open, receiver C will be in an indeterminate logic state. Receivers A and B will be in a logic zero state allowing the NOR gate to detect the short or open fault condition. The "strobe" input will disable the A and B receivers and therefore may be used to "sample" the fail-safe detector (See Figure 17).

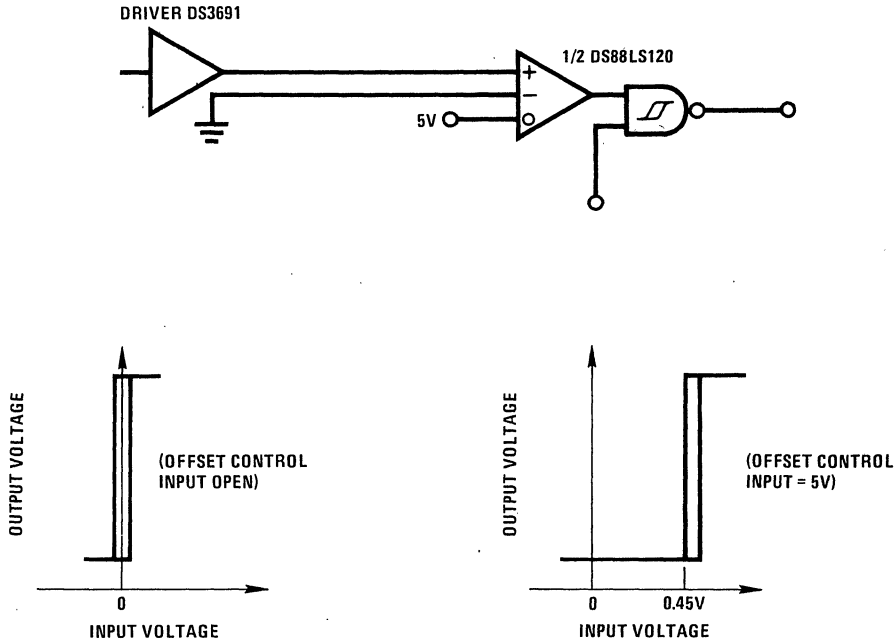


FIGURE 16. Fail-Safe Using the DS88LS120 Threshold Offset for Unbalanced Lines

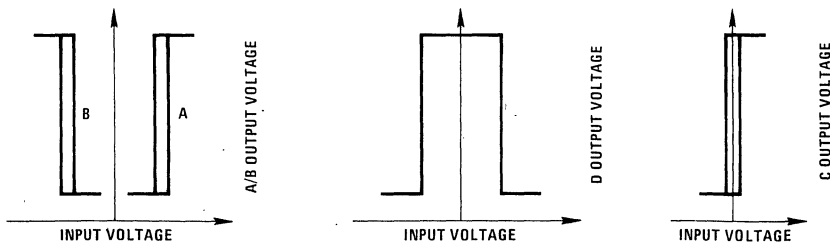
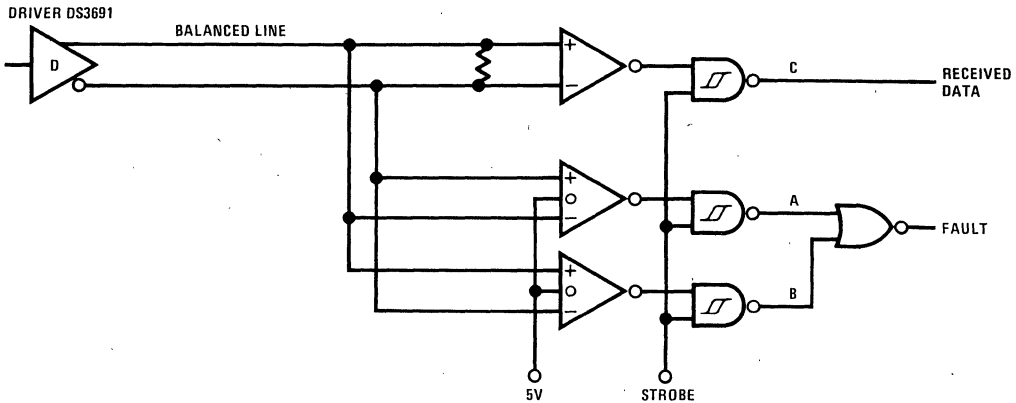


FIGURE 17. Fail-Safe Using the DS88LS120 Threshold Offset for Balanced Lines

Summary of Electrical Characteristics of Some Well Known Digital Interface Standards

National Semiconductor
Application Note 216
Don Tarver
December 1978



AN-216

1

FORWARD

Not the least of the problems associated with the design or use of data processing equipment is the problem of providing for or, actually, interconnecting the differing types and models of equipment to form specific processing systems.

The magnitude of the problem becomes apparent when one realizes that every aspect of the electrical, mechanical and architectural format must be specified. The most common of the basic decisions confronting the engineer include:

- Type of logic (negative or positive)
- Threshold levels
- Noise immunity
- Form of transmission
 - Balanced/unbalanced, terminated/unterminated
 - Unidirectional/bidirectional, simplex/multiplexed
- Type of transmission line
- Connector type and pin out
- Bit or byte oriented
- Baud rate

If each make and/or model of equipment presented a unique interface at its I/O ports, "interface" engineering would become a major expenditure associated with the use of data processing equipment.

Fortunately, this is not the case as various interested or cognizant groups have analyzed specific recurring interface areas and recommended "official" standards around which common I/O ports could be structured. Also, the I/O specifications of some equipment with widespread popularity such as the IBM 360/370 computer and DEC minicomputer have become "defacto"

standards because of the desire to provide/use equipment which interconnect to them.

Compliance with either the "official" or "defacto" standards on the part of equipment manufacturers is voluntary. However, it is obvious that much can be gained and little lost by providing equipment that offers either the "official" or "defacto" standard I/O ports.

As can be imagined, the entire subject of interface in data processing systems is complicated and confusing, particularly to those not intimately involved in the day-to-day aspects of interface engineering or management. However, at the component level the questions simplify to knowing what standards apply and what circuits or components are available to meet the standards.

This application note summarizes the important electrical characteristics of the most commonly accepted interface standards and offers recommendations on how to use National Semiconductor integrated circuits to meet those standards.

1.0 INTRODUCTION

The interface standards covered in this application note are listed in Table I. The body of the text expands upon the scope and application of each listed standard and summarizes important electrical parameters.

Table II summarizes the National Semiconductor IC's applicable to each standard.

TABLE I. COMMON LINE DRIVER/RECEIVER INTERFACE STANDARDS SUMMARY

INTERFACE AREA	APPLICATION	STANDARD	ORIGIN	COMMENTS
Data Communications Equipment (DCE*) to Data Terminal Equipment (DTE)	U.S.A. Industrial	RS232C	EIA	Unbalanced, Short Lines
		RS422	EIA	Balanced, Long Lines
		RS423	EIA	Unbalanced, RS232 Up-Grade
		RS449	EIA	System Standard Covering Use of RS422, RS423
	International	CCITT Vol. VIII V. 24 CCITT No. 97 X. 26 CCITT No. 97 X. 27	International Telephone and Telegraph Consultative Committee	Similar to RS232 Similar to RS423 Similar to RS422
U.S.A. Military	MIL-STD-188C MIL-STD-188-114 MIL-STD-1397 (NTDS-Slow) MIL-STD-1397 (NTDS-Fast)	D.O.D.	Unbalanced, Short Lines	
		D.O.D. Navy	Similar to RS422, RS423 42k bits/sec	
	Navy	250k bits/sec		
U.S. Government, Non-Military	FED-STD-1020 FED-STD-1030	GSA GSA	Identical to RS423 Identical to RS422	
Computer to Peripheral	IBM 360/370	System 360/370 Channel I/O	IBM	Unbalanced Bus
	DEC Mini-Computer	DEC Unibus®	DEC	Unbalanced Bus
Instrument to Computer	Nuclear Instrumentation	CAMAC (IEEE std. 583-1975)	NIM (AEC)	DTL/TTL Logic Levels
	Laboratory Instrumentation	488	IEEE	Unbalanced Bus
Microprocessor to Interface Devices	Microprocessor Circuits	Microbus™	National Semiconductor	Short Line; 8-Bit Parallel, Digital Transmission
Facsimile Equipment to DTE	Facsimile Transmission	RS357	EIA	Incorporates RS232
Automatic Calling Equipment to DTE	Impulse Dialing and Multi-Tone Keying	RS366	EIA	Incorporates RS232
Numerically Controlled Equipment to DTE	Numerically Controlled Equipment	RS408	EIA	Short Lines (<4 Ft.)

*Changed to "Data Circuit-Terminating Equipment"

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TABLE II. LINE DRIVER/RECEIVER INTEGRATED CIRCUIT
SELECTION GUIDE FOR DIGITAL INTERFACE STANDARDS

STANDARD DESIGNATION	PART NUMBER			
	LINE DRIVER		LINE RECEIVER	
	0°C TO +70°C	-55°C TO +125°C	0°C TO +70°C	-55°C TO +125°C
U.S. Industrial Standards				
RS232C	DS1488 DS75150	Not Applicable Not Applicable	DS1489 (A) DS75154	Not Applicable Not Applicable
RS357	See RS232C			
RS366	See RS232C			
RS408	DS75453 DS75454	DS55454 DS55454	DS7820A DS75115	DS7820A DS55115
RS422	DS3691 DS26LS31C DS3487	DS1691A DS26LS31M DS3587	DS88LS120 DS26LS32C DS3486 DS26LS33C DS88C20 DS88C120	DS78LS120 DS26LS32M DS26LS33M DS78C20 DS78C120
RS423	DS3691 DS3692	DS1691A DS1692	DS88LS120 DS88C20 DS88C120	DS78LS120 DS78C20 DS78C120
RS449	See RS422, RS423			
IEEE 488	DS3666 DS75160A DS75161A DS75162A		DS3666 DS75160A DS75161A DS75162A	
CAMAC	See RS232C, RS422, RS423 or IEEE 488			
IBM 360/370 I/O Port	DS75123	Not Applicable	DS75124	Not Applicable
DEC Unibus®	DS36147 DS8641 Transceiver	DS16147 DS7641 Transceiver	DS8640 DS8641 Transceiver	DS7640 DS7641 Transceiver
Microbus™	DS3628 DP8228 DP8216 DP8212 DP8304B Transceiver	DS1628 DP8228M DP8216M DP8212M	 DP8304B Transceiver	
Government Standards				
MIL-STD-188C	DS3692	DS1692	DS88LS120	DS78LS120
MIL-STD-188-114	DS3692	DS1692	DS88LS120	DS78LS120
FED-STD-1020	See RS423			
FED-STD-1030	See RS422			
MIL-STD-1397 (NTDS-Slow)	Use Discrete Components and/or Comparators			
MIL-STD-1397 (NTDS-Fast)	Use Discrete Components and/or Comparators			

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TABLE II. LINE DRIVER/RECEIVER INTEGRATED CIRCUIT SELECTION GUIDE FOR DIGITAL INTERFACE STANDARDS (Continued)

STANDARD DESIGNATION	PART NUMBER			
	LINE DRIVER		LINE RECEIVER	
	0°C TO +70°C	-55°C TO +125°C	0°C TO +70°C	-55°C TO +125°C
International Standards (CCITT)				
1969 White Book Vol. VIII, V. 24	See RS232C			
Circular No. 97, X. 26	See RS422			
Circular No. 97, X. 27	See RS423			

2.0 DATA TERMINAL EQUIPMENT (DTE) TO DATA COMMUNICATIONS EQUIPMENT (DCE) INTERFACE STANDARDS

2.1 Application

The DTE/DCE standards cover the electrical, mechanical and functional interface between/ among terminals (i.e., teletypewriters, CRTs, etc.) and communications equipment (i.e., modems, cryptographic sets, etc.).

2.2 U.S. Industrial DTE/DCE Standards

2.2.1 EIA RS232C

The oldest and most widely known DTE/DCE standard. It provides for one-way/non-reversible, single-ended (unbalanced), non-terminated line, serial digital data transmission.

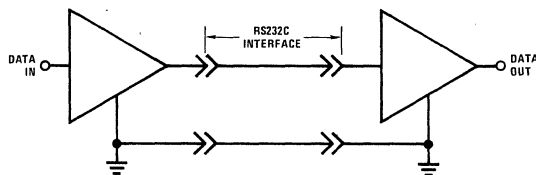


FIGURE 1. EIA RS232C Application

Important features are:

- Positive logic ($\pm 5V$ min to $\pm 15V$ max)
- Fault protection
- Slew-rate control
- 50 feet recommended cable length and 20k bits per second data signaling rate.

2.2.2 EIA RS422, RS423

In a move to upgrade system capabilities by utilizing state-of-the-art devices and

technology the EIA, in 1975, introduced 2 new specifications covering:

- Single-ended data transmission at modulation rates up to kilobaud* (RS423)
- Balanced data transmission at modulation rates up to 10 megabaud (RS422).

2.2.2.1 RS423

RS423 closely resembles RS232C in that it, too, specifies one-way/non-reversible, single-ended, data transmission lines. Key differences between RS423 and RS232C are:

RS423

4V to 6V Logical "1"
-4V to -6V Logical "0"
100k Baud at 40 Feet
Balanced Receiver, Referred to Driver Ground, Permitting Ground Potential Difference Between Driver and Receiver

RS232

5V to 15V Logical "1"
-5V to -25V Logical "0"
20k Baud at 50 Feet
Unbalanced Receiver

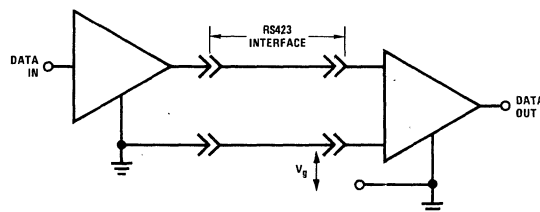


FIGURE 2. EIA RS423 Application

* Modulation rate = reciprocal of minimum pulsewidth (i.e., 20 ms pulse = 50 baud)

TABLE III. EIA RS232C SPECIFICATION SUMMARY

PARAMETER	CONDITIONS	EIA RS232C			UNITS
		MIN	TYP	MAX	
V _{OH}	Driver Output Voltage Open			25	V
V _{OL}	Circuit	-25			V
V _{OH}	Driver Output Voltage Loaded	3 k Ω \leq R _L \leq 7 k Ω	5	15	V
V _{OL}	Output		-15	-5	V
R _O	Driver Output Resistance Power OFF	-2V \leq V _O \leq 2V		300	Ω
I _{OS}	Driver Output Short-Circuit Current		-500	500	mA
	Driver Output Slew Rate				
	All Interchange Circuits			30	V/ μ s
	Control Circuits		6		V/ms
	Rate and Timing Circuits		6		V/ms
	% of Unit Interval		4		%
R _{IN}	Receiver Input Resistance	3V \leq V _{IN} \leq 25V	3000	7000	Ω
	Receiver Open Circuit Input Bias Voltage		-2	2	V
	Receiver Input Threshold				
	Output = MARK		-3		V
	Output = SPACE			3	V

TABLE IV. EIA RS423 SPECIFICATION SUMMARY

PARAMETER	CONDITIONS	EIA RS423			UNITS
		MIN	TYP	MAX	
V _O	Driver Unloaded Output Voltage	4		6	V
\overline{V}_O		-4		-6	V
V _T	Driver Loaded Output Voltage	R _L = 450 Ω	3.6		V
\overline{V}_T			-3.6		V
R _S	Driver Output Resistance			50	Ω
I _{OS}	Driver Output Short-Circuit Current	V _O = 0V		\pm 150	mA
	Driver Output Rise and Fall Time	Baud Rate \leq 1k Baud		300	μ s
		Baud Rate \geq 1k Baud		30	% Unit Interval
I _{OX}	Driver Power OFF Current	V _O = \pm 6V		\pm 100	μ A
V _{TH}	Receiver Sensitivity	V _{CM} \leq \pm 7V		\pm 200	mV
V _{CM}	Receiver Common-Mode Range			\pm 10	V
R _{IN}	Receiver Input Resistance		4000		Ω
	Receiver Common-Mode Input Offset			\pm 3	V

2.2.2.2 RS422

RS422 provides for balanced data transmission with unidirectional/non-reversible, terminated or non-terminated transmission lines. Important features are:

- a) $\pm 2V$ to $\pm 6V$ driver output
- b) 0.4V differential output matching
- c) ± 200 mV receiver input sensitivity
- d) 10M baud modulation rate

2.3 International Standards

2.3.1 CCITT 1969 White Book Vol. VIII, V. 24. This standard is identical to RS232C.

2.3.2 CCITT circular No. 97 Com SPA/13, X. 26. This standard is similar to RS422 with the exception that the receiver sensitivity at the specified maximum common-mode voltage ($\pm 7V$) shall be ± 300 mV vs ± 200 mV for RS422.

2.3.3 CCITT circular No. 97 Com SPA/13, X. 27. This standard is similar to RS422 with 2 exceptions:

- a) The receiver sensitivity is as specified in paragraph X. 26, and
- b) The driver output voltage is specified at a load resistance of 3.9 k Ω .

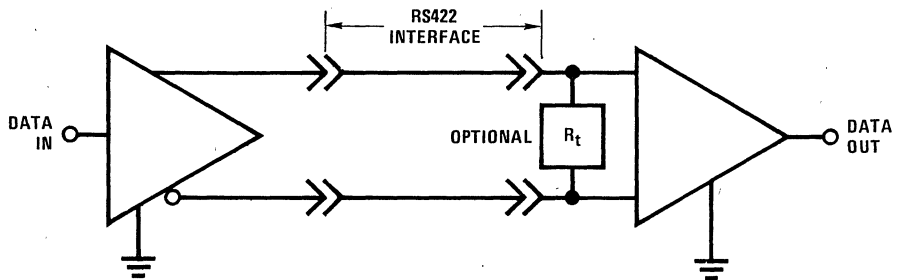


FIGURE 3. EIA RS422 Application

TABLE V. EIA RS422 SPECIFICATION SUMMARY

PARAMETER	CONDITIONS	EIA RS422			UNITS
		MIN	TYP	MAX	
V_O	Driver Unloaded Output Voltage			6	V
\bar{V}_O				-6	V
V_T	Driver Loaded Output Voltage				V
\bar{V}_T		2			V
R_S	Driver Output Resistance			50	Ω
I_{OS}	Driver Output Short-Circuit Current			150	mA
	Driver Output Rise Time			10	% Unit Interval
I_{OX}	Driver Power OFF Current			± 100	μA
V_{TH}	Receiver Sensitivity			200	mV
V_{CM}	Receiver Common-Mode Voltage	-12		12	V
	Receiver Input Offset	± 3			V

2.4 U.S. Military Standards

2.4.1 MIL-STD-188C (Low Level)

The military equivalent to RS232C is MIL-STD-188C. Devices intended for

RS232C can be applied to MIL-STD-188C by use of external wave shaping components on the driver end and input resistance and threshold tailoring on the receiver end.

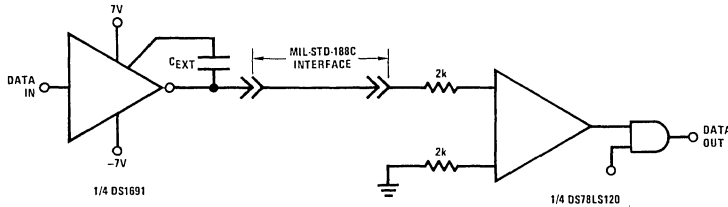


FIGURE 4. MIL-STD-188C Application

TABLE VI. MIL-STD-188C SPECIFICATION SUMMARY

PARAMETER	CONDITIONS	MIL-STD-188C LOW LEVEL LIMITS			UNITS
		MIN	TYP	MAX	
V _{OH}	Driver Output Voltage Open Circuit	(Note 1)	5	7	V
V _{OL}	Driver Output Voltage Open Circuit	(Note 1)	-7	-5	V
R _O	Driver Output Resistance Power ON	I _{OUT} ≤ 10 mA		100	Ω
I _{OS}	Driver Output Short-Circuit Current		-100	100	mA
	Driver Output Slew Rate				
	All Interchange Circuits	(Note 2)	5	15	% I _U
	Control Circuits				
	Rate and Timing Circuits				
R _{IN}	Receiver Input Resistance	Mod Rate ≤ 200k Baud	6		Ω
	Receiver Input Threshold				
	Output = MARK	(Note 3)		100	μA
	Output = SPACE		-100		μA

Note 1: Ripple < 0.5%, V_{OH}, V_{OL} matched to within 10% of each other.

Note 2: Waveshaping required on driver output such that the signal rise or fall time is 5% to 15% of the unit interval at the applicable modulation rate.

Note 3: Balance between marking and spacing (threshold) currents actually required shall be within 10% of each other.

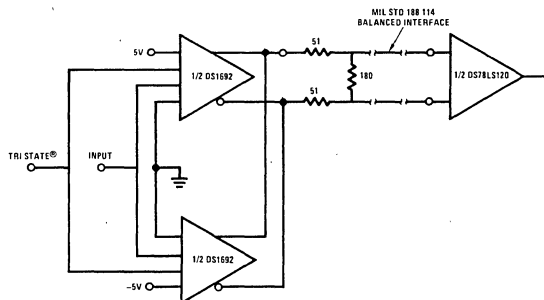


FIGURE 5. MIL-STD-188-114 (Balanced Applications)

2.4.2 MIL-STD-188-114 Balanced

This standard is similar to RS422 with the exception that the driver offset voltage level is limited to $\pm 0.4V$ vs $\pm 3V$ allowed in RS422.

2.4.3 MIL-STD-188-114 Unbalanced.

This standard is similar to RS423 with the exception that loaded circuit driver output voltage at $R_L = 450\Omega$ must be 90% of the open circuit output voltage vs $\pm 2V$ at $R_S = 100\Omega$ for RS422.

2.4.4 MIL-STD-1397 (Slow and Fast)

2.5 U.S. Government (non-military) standards FED-STD-1020 and 1030 are identical with-out exception to EIA RS423 and RS422, respectively.

3.0 COMPUTER TO PERIPHERAL INTERFACE STANDARDS

To date, the only standards dealing with the interface between processors and other equipment are the "defacto" standards in the form of specifications issued by IBM and DEC covering the models 360/370 I/O ports and the Unibus®, respectively.

3.1 IBM specification GA-22-6974-0 covers the electrical characteristics, the format of information and the control sequences of the data transmitted between 360/370's and up to 10 I/O ports.

The interface is an unbalanced bus using 95Ω , terminated, coax cables. Devices connected to the bus should feature short-circuit protection, hysteresis in the receivers, and open-emitter drivers. Careful attention should be paid to line lengths and quality in order to limit cable noise to less than 400 mV.

TABLE VII. MIL-STD-1397 SPECIFICATION SUMMARY

PARAMETER	CONDITIONS	COMPARISON LIMITS (MIL-STD)		UNITS
		1397 (SLOW)	1397 (FAST)	
Data Transmission Rate		42	250	k Bits/Sec
V_{OH}	Driver Output Voltage	± 1.5	0	V
V_{OL}		-10 to -15.5	-3	V
I_{OH}	Driver Output Current	≥ -4		mA
I_{OL}		1		mA
R_S	Driver Power OFF Impedance	≥ 100		k Ω
V_{IH}	Receiver Input Voltage	≤ 4.5	≤ -1.1	V
V_{IL}	Fail-Safe Open Circuit	≥ -7.5	≥ -1.9	V

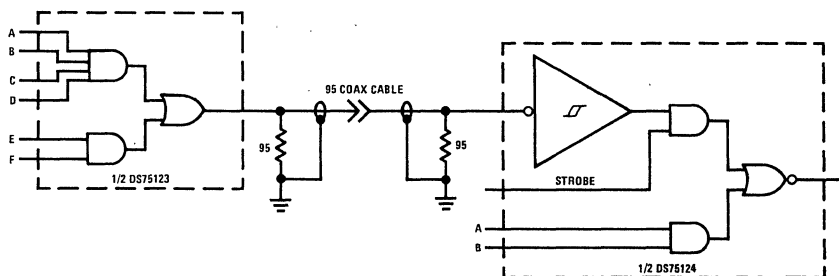


FIGURE 6. IBM 360/370 I/O Application

TABLE VIII. IBM 360/370 SPECIFICATION SUMMARY

PARAMETER	CONDITIONS	IBM 360/370			UNITS
		MIN	TYP	MAX	
V_{OH}	Driver Output Voltage			7	V
V_{OH}				5.85	V
V_{OH}		3.11			V
V_{OL}				0.15	V
V_{IH}	Receiver Input Threshold			1.7	V
V_{IL}	Voltage	0.7			V
I_{IH}	Receiver Input Current	$V_{IN} = 3.11V$		-0.42	mA
I_{IL}		$V_{IN} = 0.15V$	0.24		mA
	Receiver Input Voltage Range				
V_{IN}	Power ON		-0.15	7	V
V_{IN}	Power OFF		-0.15	6	V
R_{IN}	Receiver Input Impedance	$0.15V \leq V_{IN} \leq 3.9V$	7400		Ω
I_{IN}	Receiver Input Current	$V_{IN} = 0.15V$		240	μA
Z_0	CABLE Impedance		83	101	Ω
R_0	CABLE Termination	$P_D \geq 390 mW$	90	100	Ω
	Line Length (Specified as Noise on Signal and Ground Lines)			400	mV

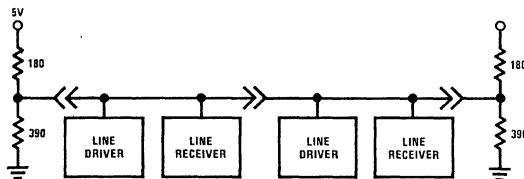


FIGURE 7. DEC Unibus® Application

TABLE IX. DEC UNIBUS® SPECIFICATION SUMMARY

PARAMETER	CONDITIONS	DEC UNIBUS®			UNITS
		MIN	TYF	MAX	
V_{OL}	Driver Output Voltage			0.7	V
V_O	Absolute Maximum			7	V
V_{IH}	Receiver Input Voltage	1.7			V
V_{IL}				1.3	V
I_{IH}	Receiver Input Current	$V_{IN} = 4V$		100	μA
I_{IL}		$V_{IN} = 4V$ Power OFF		100	μA

3.2 DEC Unibus®

Another example of an unofficial industry standard is the interface to a number of DEC minicomputers. This interface, configured as a 120Ω double-terminated data bus is given the

name Unibus®. Devices connected to the bus should feature hysteresis in the receivers and open-collector driver outputs. Cable noise should be held to less than 600 mV.

4.0 INSTRUMENTATION TO COMPUTER INTER-FACE STANDARDS

4.1 Introduction

The problem of linking instrumentation to processors to handle real-time test and measurement problems was largely a custom interface problem. Each combination of instruments demanded unique interfaces, thus inhibiting the wide spread usage of small processors to day-to-day test, measurement and control applications.

Two groups addressed the problem for specific environments. The results are:

- a) IEEE 488 bus standard based upon proposals made by HP, and

- b) The CAMAC system pioneered by the nuclear physics community.

4.2 IEEE 488

IEEE 488 covers the functional, mechanical and electrical interface between laboratory instrumentation (i.e., signal generators, DPM's, counters, etc.) and processors such as programmable calculators and minicomputers. Equipment with IEEE 488 I/O ports can be readily daisy chained in any combination of up to 15 equipments (including processor) spanning distances of up to 60 feet. 16 lines (3 handshake, 5 control and 8 data lines) are required.

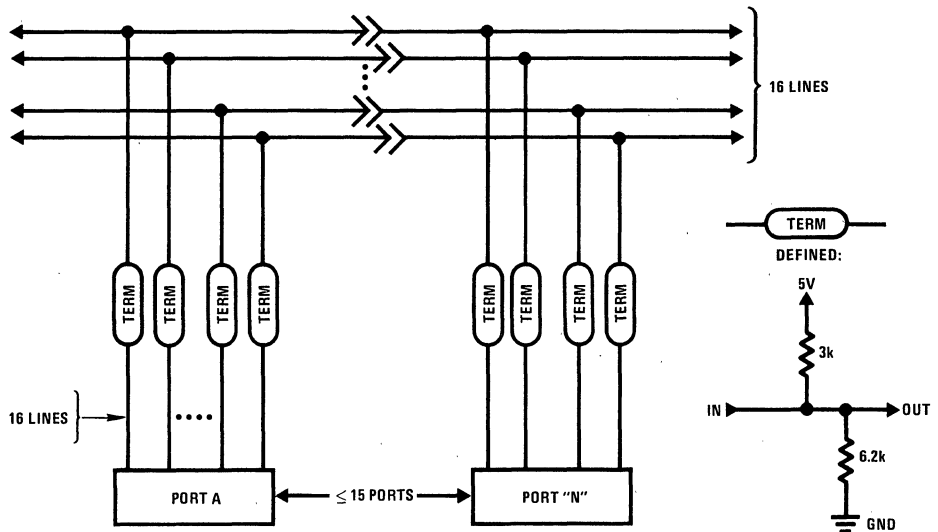


FIGURE 8. IEEE 488 Application

TABLE X. IEEE 488 SPECIFICATION SUMMARY

PARAMETER	CONDITIONS	IEEE 488			UNITS
		MIN	TYP	MAX	
VOH	Driver Output Voltage				V
VOL	Driver Output Voltage				V
IOZ	Driver Output Current TRI-STATE®			±40	µA
IOH	Open Collector			250	µA
VIH	Receiver Input Voltage	0.4V Hysteresis Recommended	2.0		V
VIL	Receiver Input Voltage			0.8	V
IiH	Receiver Input Current	VIN = 2.4V		40	µA
IiL	Receiver Input Current	VIN = 0.4V		-1.6	mA
	Receiver Clamp Current	VIN = -1.5V		12	mA
RL1	Termination Resistor	VCC = 5V (±5%)	2850	3150	
RL2	Termination Resistor	V = Gnd	5890	6510	

4.3 CAMAC

The CAMAC system is the result of efforts by those in the nuclear physics community to standardize the interface between laboratory instruments and computers before the introduction of IEEE 488.

It allows either serial or parallel interconnection of instruments via a "crate" controller.

The electrical requirements of the interfaces are compatible with DTL and TTL logic levels.

- a) Minimal system: for data transfer over short distances (usually on 1 PC board), and,
- b) Expanded system: for data transfer to extend the memory or computational capabilities of the system.

5.2 Minimal Systems and Microbus™

Microbus™ considers the interface between MOS/LSI microprocessors and interfacing devices in close physical proximity which communicate over 8-bit parallel unified bus systems. It specifies both the functional and electrical characteristics of the interface and is modeled after the 8060, 8080 and 8900 families of microprocessors as shown in *Figures 8, 9 and 10*.

The electrical characteristics of Microbus are shown in Table XI.

5.0 MICROPROCESSOR SYSTEMS INTERFACE STANDARDS

5.1 Microprocessor systems are bus organized systems with two types of bus requirements:

TABLE XI. MICROBUS ELECTRICAL SPECIFICATION SUMMARY

PARAMETER	DRIVER	RECEIVER		UNITS
		STANDARD	HYSTERESIS (RECOMMENDED)	
V _{OL}	Output Voltage (At 1.6 mA)	≤0.4V		
V _{OH}	(At -100 μA)	≥2.4V		
V _{IL}	Input Voltage	0.8	0.6	V
V _{IH}		2.0	2.0	V
	Internal Capacitive Load at 25°C	15	10	pF
t _r	Rise Time (Maximum)	100		ns
t _f	Fall Time (Maximum)	100		ns

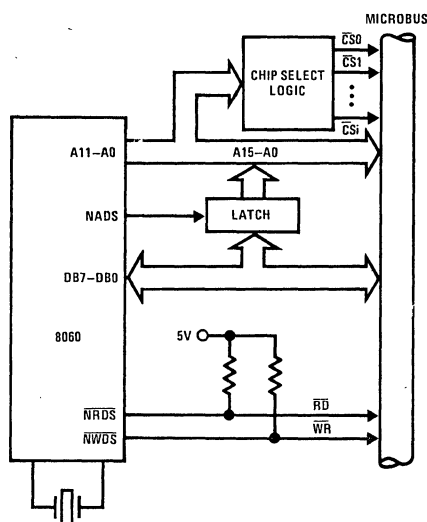


FIGURE 9. 8060 SC/MP II System Model

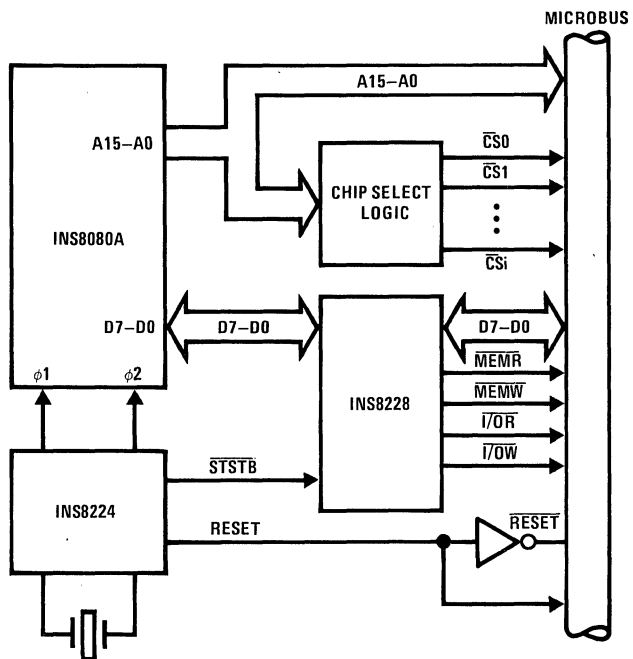


FIGURE 10. 8080 System Model for the Basic Microbus Interface

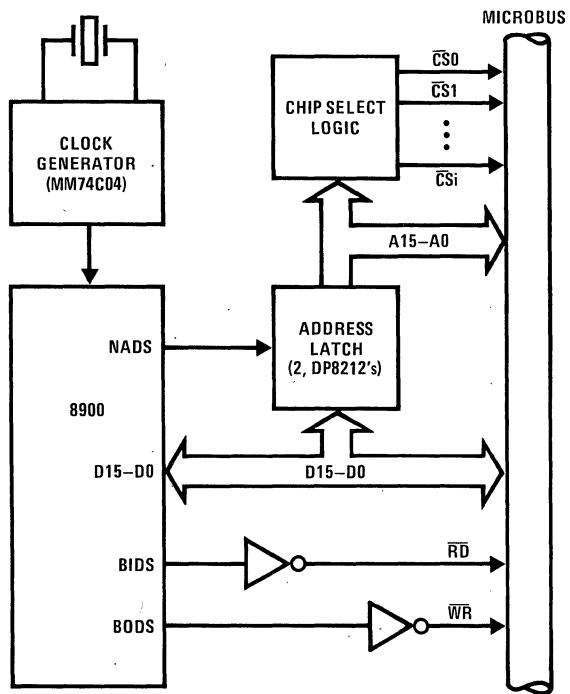


FIGURE 11. 8900 System Model

5.3 Expanded Microprocessor System Interfaces

Since the outputs of most microprocessor devices are limited to a loading of one relative to a TTL load, expanded systems will require buffers on both their address and data lines.

To date, no formal standards exist which govern this interface. However, "defacto" standards are emerging in the form of the specifications for "recommended devices" which are mentioned in the data sheets and application notes for the widely sourced microprocessor devices. Here, the answer to the question of how to provide a "standard" interface is simplified to that of proper usage of recommended devices.

Table XII summarizes the important electrical characteristics of recommended bus drivers for expanded microprocessor systems.

6.0 OTHER INTERFACE STANDARDS

Some other commonly occurring interfaces which have become standardized are:

- a) Interface between facsimile terminals and voice frequency communications terminals,

- b) Interface between terminals and automatic calling equipment used for data communications, and
- c) Interface between numerically controlled equipment and data terminals.

6.1 EIA RS357

RS357 defines the electrical, functional and mechanical characteristics of the interface between analog facsimile equipment to be used for telephone data transmission and the data sets used for controlling/transmitting the data.

Figure 11 summarizes the functional and electrical characteristics of RS357.

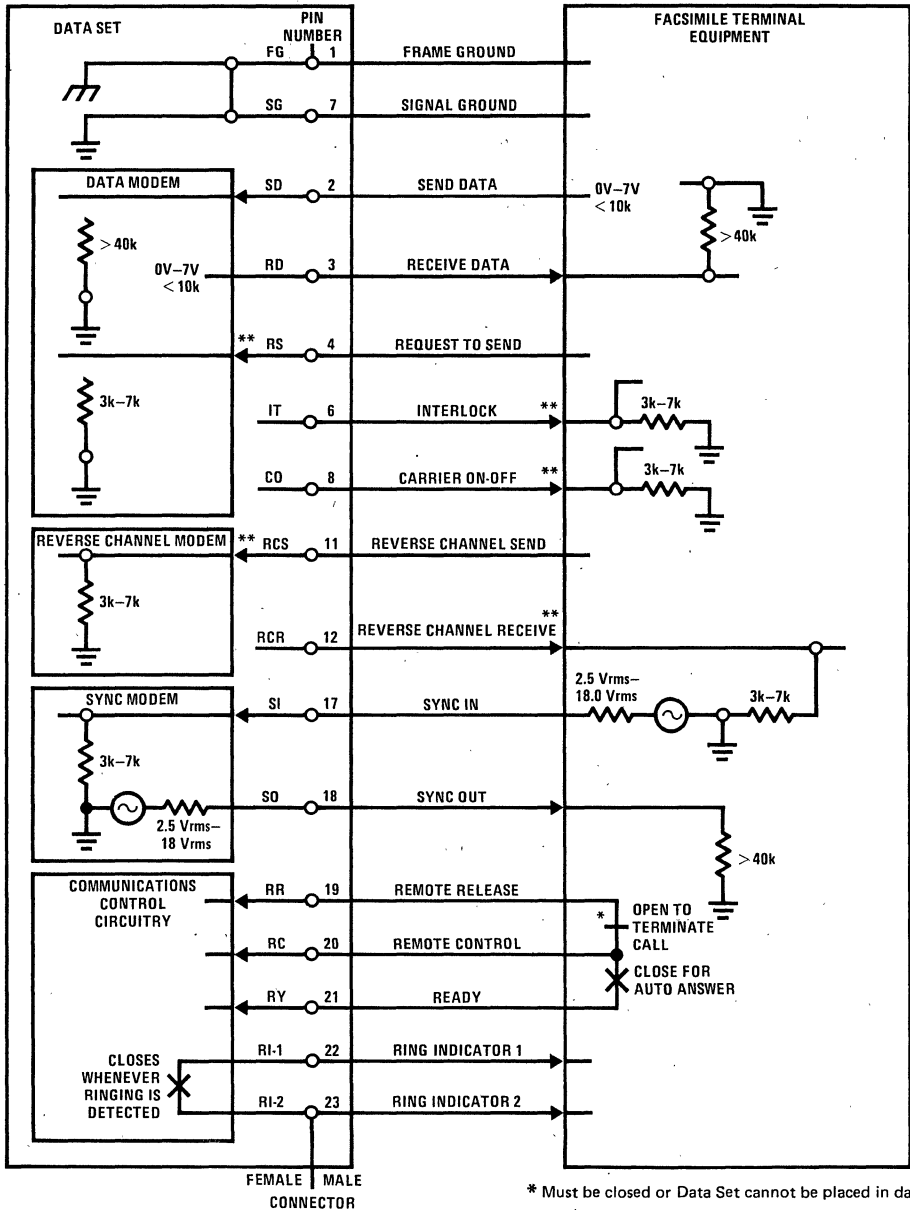
6.2 EIA RS366

RS366 defines the electrical, functional and mechanical characteristics of the interface between automatic calling equipment for data communications and data terminal equipment.

The electrical characteristics are encompassed by RS232C.

TABLE XII. RECOMMENDED SPECIFICATION OF BUS DRIVERS FOR EXPANDED MICROPROCESSOR SYSTEMS

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{IH}	Driver Input Voltage	2			V
V _{IL}				0.8	V
V _{OH}	Driver Output Voltage	2.4			V
V _{OL}	I _{OH} = -10 mA I _{OL} = 48 mA			0.5	V
I _{OS}	Short-Circuit Current V _{CC} = 5.25V			-150	mA
C _L	Bus Drive Capability	300			pF



** Receive Sensitivity	Source
ON	3V-25V 5V-25V
OFF	3V-25V 5V-25V

FIGURE 12. Functional and Electrical Characteristics of RS357

6.3 EIA RS408

RS408 recommends the standardization of the 2 interfaces shown in Figure 13.

The electrical characteristics of NCE to DTE interface are, in summary, those of conventional TTL drivers (series 7400) with:

$$V_{OL} \leq 0.4V \text{ at } I_{OL} = 48 \text{ mA}$$

$$V_{OH} \geq 2.4V \text{ at } I_{OH} \leq -1.2 \text{ mA, and}$$

$$C_L \leq 2000 \text{ pF.}$$

Short circuit protection should be provided.

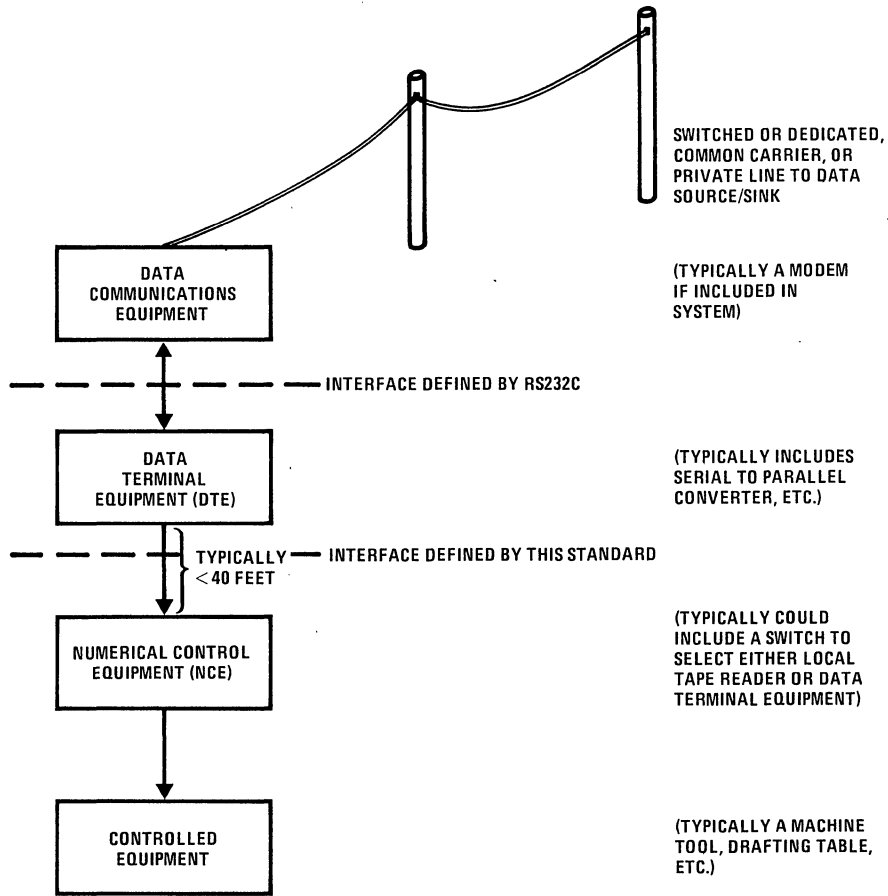


FIGURE 13. EIA RS408 Interface Applications



Section 2 Bus Transceivers

2

TEMPERATURE RANGE		DESCRIPTION	PAGE NUMBER
- 55°C to + 125°C	0°C to + 70°C		
*DP7303	DP8303	8-Bit TRI-STATE Bidirectional Transceivers	2-5, 2-6
*DP7304B	DP8304B	8-Bit TRI-STATE Bidirectional Transceivers	2-5, 2-11
*DP7307	DP8307	8-Bit TRI-STATE Bidirectional Transceivers	2-5, 2-16
*DP7308	DP8308	8-Bit TRI-STATE Bidirectional Transceivers	2-5, 2-20
*DS26S10M	DS26S10	Quad Bus Transceiver	2-24
*DS26S11M	DS26S11	Quad Bus Transceiver	2-24
—	DS3662	Quad High Speed Trapezoidal Bus Transceiver	2-29
—	AN-259	DS3662—The Bus Optimizer	2-33
—	AN-337	Reducing Noise on Microcomputer Buses	2-40
—	DS3666	IEEE-488 GPIB Transceiver	2-48
—	DS3667	TRI-STATE Bidirectional Transceiver	2-56
—	DS75160A	IEEE-488 GPIB Transceiver	2-61
—	DS75161A	IEEE-488 GPIB Transceiver	2-61
—	DS75162A	IEEE-488 GPIB Transceiver	2-61
*DS7640	DS8640	Quad NOR Unified Bus Receiver	2-68
*DS7641	DS8641	Quad Unified Bus Transceiver	2-70
—	DS8642	Quad Transceiver	2-72
*DS7833	DS8833	Quad TRI-STATE Bus Transceiver	2-75
*DS7834	DS8834	Quad TRI-STATE Bus Transceiver	2-79
*DS7835	DS8835	Quad TRI-STATE Bus Transceiver	2-75
*DS7836	DS8836	Quad NOR Unified Bus Transceiver	2-83
*DS7837	DS8837	Hex Unified Bus Receiver	2-85
*DS7838	DS8838	Quad Unified Bus Transceiver	2-87
*DS7839	DS8839	Quad TRI-STATE Bus Transceiver	2-79
DS8T26AM	DS8T26A	4-Bit Bidirectional Bus Transceiver	2-89
*DS8T28M	DS8T28	4-Bit Bidirectional Bus Transceiver	2-89
DM54S240	DM74S240	Octal TRI-STATE Line Driver/Receiver	LOGIC
DM54S241	DM74S241	Octal TRI-STATE Line Driver/Receiver	LOGIC

*Also available screened in accordance with MIL-STD-883 Class B. Refer to National Semiconductor's "The Reliability Handbook".

BUS CIRCUITS

Data bus circuits are not transmission line circuits in the normal interpretation where the transmission line is electrically long (1/4 wave length) with respect to the baud rate. Like unbalanced transmission lines, the data transmission is susceptible to common-mode noise, such as ground IR noise and induced reactive noise from crosstalk. A bus is a communications method where many elements of a system time share the same signal (address or data) bus. A bus shouldn't extend out of its subsystem's electronic enclosure without special care. Line length in excess of 10 feet is not recommended without slew rate control. Cables should be in the form of twisted pair or flat cable where a signal wire is alternated with a ground wire.

OPEN-COLLECTOR BUS CIRCUITS

Bus Driver		Bus Receiver				Driver/ Receiver/ Transceiver	Circuits/ Package	Device Number		Comments	Page No.		
Propagation Delay (ns)	V _{IL} (V)/ I _{OL} (mA)	Propagation Delay (ns)	V _{IL} (V)/ I _{IL} (μA)	V _{IH} (V)/ I _{IH} (μA)	Hysteresis (V)			Commercial 0°C to +70°C	Military -55°C to +125°C				
23	0.9/100	23	1.2/-50	1.8/50	1	Receiver	4	DS8640	DS7640	Quad NOR receiver	2-68		
		20	1.05/-50	2.65/50		Receiver	4	DS8836	DS7836	Quad NOR receiver	2-83		
		20	1.05/-50	2.65/50		Receiver	6	DS8837	DS7837		2-85		
		40	1.50/400	1.9/100		Transceiver	4	DS3662		Trapezoidal transceiver	2-29		
		30	0.7/50	1.2/-100		1.8/100	Transceiver	4	DS8641	DS7641		2-70	
		20	0.7/50	1.05/-100		2.65/100	Transceiver	4	DS8642			2-72	
		20	0.8/100	20		1.3/-40	3.1/450	Transceiver	4	DS8838	DS7838	50Ω coax. driver	2-87
		10	0.8/100	10		1.75/-100	2.25/100	Transceiver	4	DS26S10	DS26S10M		2-24
		10	0.8/100	10		1.75/-100	2.25/100	Transceiver	4	DS26S11	DS26S11M	Input to bus is non-inverting	2-24
		8	0.5/50	7		0.8/-500	2/100	Transceiver	4	DS36147	DS16147	Quad bidirectional I/O register	6-35
		8	0.5/50	7		0.8/-500	2/100	Transceiver	4	DS36177	DS16177	Quad bidirectional I/O register	6-35
		20	0.7/300					Driver	2	DS75450	DS55450	AND separate output transistors	3-51
		18	0.7/300					Driver	2	DS75451	DS55451	AND	3-51
		26	0.7/300					Driver	2	DS75452	DS55452	NAND	3-51
		18	0.7/300					Driver	2	DS75453	DS55453	OR	3-51
		27	0.7/300					Driver	2	DS75454	DS55454	NOR	3-51
				30		0.95/50	2/50	0.65	Receiver	1	DM8131	DM7131	6 bit bus comparator
		30	0.95/50	2/50	0.65	Receiver	1	DM8136	DM7136	6 bit bus comparator	LOGIC		

TRI-STATE® BUS CIRCUITS

Bus Driver			Bus Receiver				Driver/ Receiver/ Transceiver	Circuits/ Package	Device Number		Comments	Page No.
Propagation Delay Typ (ns)	VOL (V)/ IOL (mA)	VOH (V)/ IOH (mA)	Propagation Delay Typ (ns)	VIL (V)/ IIL (μA)	VIH (V)/ IIH (μA)	Hysteresis (mV)			Commercial	Military		
									0°C to +70°C	-55°C to +125°C		
14	0.5/50	2.4/-10	20	0.8/-40	2/80	400	Transceiver	4	DS8833	DS7833	Non-inverting TRI-STATE receiver	2-75
14	0.5/50	2.4/-10	20	0.8/-40	2/80	400	Transceiver	4	DS8835	DS7835	Inverting TRI-STATE receiver	2-75
14	0.5/50	2.4/-10	20	0.8/-40	2/80	400	Transceiver	4	DS8834	DS7834	Inverting	2-79
14	0.5/50	2.4/-10	20	0.8/-40	2/80	400	Transceiver	4	DS8839	DS7839	Non-inverting	2-79
14	0.5/48	2.4/-10	14	0.85/-200	2/20		Transceiver	4	DS8T26A	DS8T26AM	Inverting	2-89
17	0.5/48	2.4/-10	17	0.85/-200	2/20		Transceiver	4	DS8T28	DS8T28M	Non-inverting	2-89
20	0.6/55	3.6/-1	15	0.95/-250	2/10		Transceiver	4	DP8216	DP8216M	8080 MPU non-inverting	8-11
16	0.6/50	3.6/-1	15	0.95/-250	2/10		Transceiver	4	DP8226	DP8226M	8080 MPU inverting	8-11
4.5	0.55/64	2.4/-3	4.5	0.8/-400	2/50	400	Transceiver	4 or 8	DM74S240	DM54S240	Non-Inverting	LOGIC
6	0.55/64	2.4/-3	6	0.8/-400	2/50	400	Transceiver	4 or 8	DM74S241	DM54S241	Inverting	LOGIC
4.5	0.55/64	2.4/-3	4.5	0.8/-400	2/50	400	Transceiver	8	DM74S940	DM54S940	Non-Inverting	LOGIC
6	0.55/64	2.4/-3	6	0.8/-400	2/50	400	Transceiver	8	DM74S941	DM54S941	Inverting	LOGIC
8	0.5/50	2.4/-5	7	0.8/-500	2/100		Transceiver	4	DS3647	DS1647	Quad bidirectional I/O register	6-35
8	0.5/50	2.4/-5	7	0.8/-500	2/100		Transceiver	4	DS3677	DS1677	Quad bidirectional I/O register	6-35
10	0.5/50	3.6/-5	15	0.8/-250	2/80		Transceiver	8	DP8304B	DP7304B	Bidirectional non-inverting IEEE 488	2-5, 2-11
10	0.5/50	3.6/-5	10	0.8/-250	2/80		Transceiver	8	DP8303	DP7303	Bidirectional inverting	2-5, 2-6
10	0.5/50	3.6/-5	10	0.8/-250	2/80		Transceiver	8	DP8307	DP7307	Bidirectional inverting	2-5, 2-16
11	0.5/50	3.6/-5	15	0.8/-250	2/80		Transceiver	8	DP8308	DP7308	Bidirectional non-inverting	2-5, 2-20
20	0.45/15	3.6/-1					Driver	8	DP8212	DP8212M	8080 MPU data latch and service request f/f	8-4
30	0.45/10	2.4/-1	20	0.8/-250	2/20		Transceiver	8	DP8228	DP8228M	8080 MPU system bus controller and bus driver	8-22
30	0.45/10	2.4/-1	20	0.8/-250	2/20		Transceiver	8	DP8238	DP8238M	8080 MPU system bus controller and bus driver	8-22
20	0.5/48	2.5/-5.2	20	0.8/-100	2/20	400	Transceiver	8	DS3666		IEEE 488 GPIB	2-48
20	0.5/48	2.5/-5.2	20	0.8/-100	2/20	400	Transceiver	8	DS3667			2-56
20	0.5/48	2.5/-5.2	20	0.8/-100	2/20	400	Transceiver	8	DS75160A		IEEE 488 GPIB	2-61
20	0.5/48	2.5/-5.2	20	0.8/-100	2/20	400	Transceiver	8	DS75161A		IEEE 488 GPIB	2-61
20	0.5/48	2.5/-5.2	20	0.8/-100	2/20	400	Transceiver	8	DS75162A		IEEE 488 GPIB	2-61

Note. Unless otherwise specified, bus circuits listed above are TTL compatible and use 5V supplies.

8-Bit TRI-STATE® Bidirectional Transceivers

- DP7303/DP8303 (Inverting) with $\overline{\text{Transmit/Receive}}$ and $\overline{\text{Chip Disable}}$ Control Inputs
- DP7304B/DP8304B (Non-Inverting) with $\overline{\text{Transmit/Receive}}$ and $\overline{\text{Chip Disable}}$ Control Inputs
- DP7307/DP8307 (Inverting) with $\overline{\text{Transmit}}$ and $\overline{\text{Receive}}$ Control Inputs
- DP7308/DP8308 (Non-Inverting) with $\overline{\text{Transmit}}$ and $\overline{\text{Receive}}$ Control Inputs

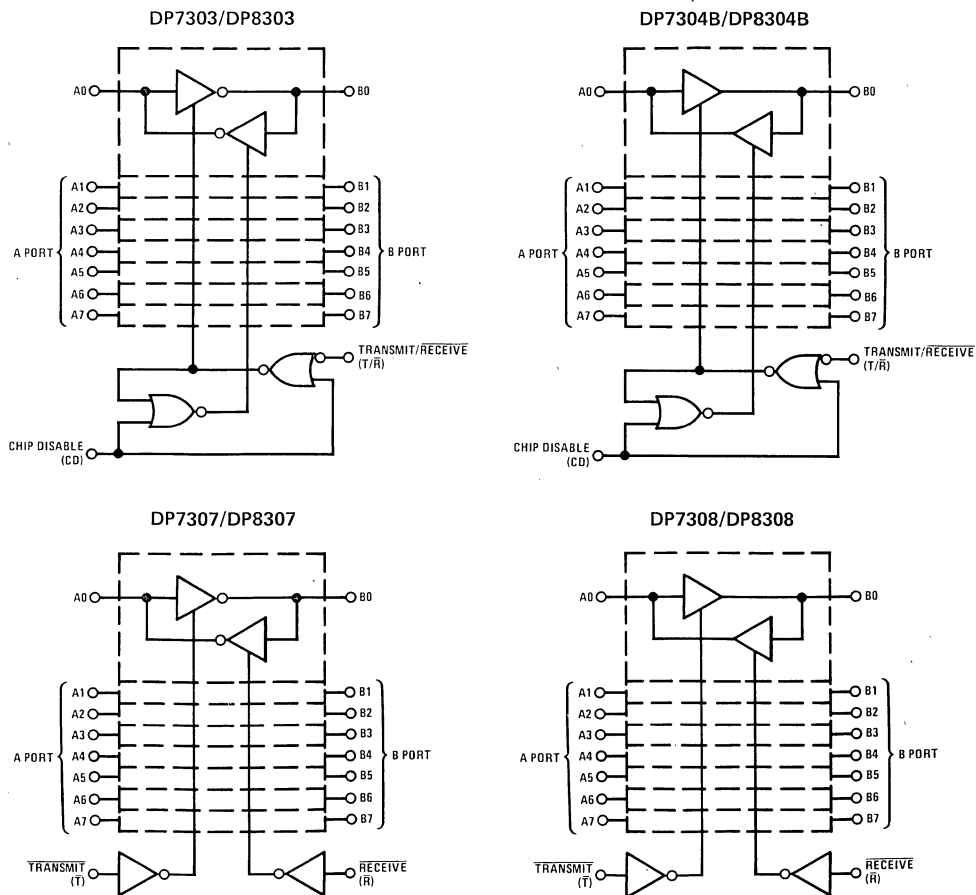
General Description

This family of 8 high speed Schottky 8-bit TRI-STATE bidirectional transceivers are designed to provide bi-directional drive for bus oriented microprocessor and digital communications systems. They are all capable of sinking 16 mA on the A ports and 48 mA on the B ports (bus ports). PNP inputs for low input current and an increased output high (V_{OH}) level allow compatibility with MOS, CMOS, and other technologies that have a higher threshold and less drive capabilities. In addition, they all feature glitch-free power up/down

on the B port preventing erroneous glitches on the system bus in power up or down.

DP7303/DP8303 and DP7304B/DP8304B are featured with $\overline{\text{Transmit/Receive}}$ (T/R) and $\overline{\text{Chip Disable}}$ (CD) inputs to simplify control logic. For greater design flexibility, DP7307/DP8307 and DP7308/DP8308 are featured with $\overline{\text{Transmit}}$ (T) and $\overline{\text{Receive}}$ (R) control inputs.

Logic Diagrams

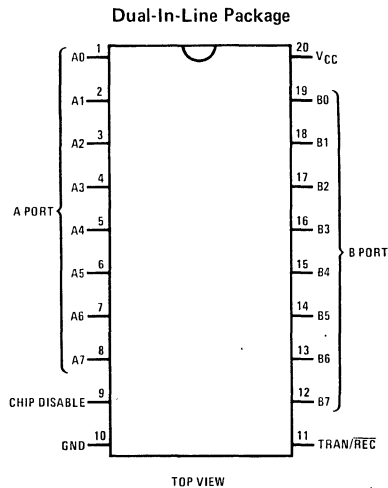
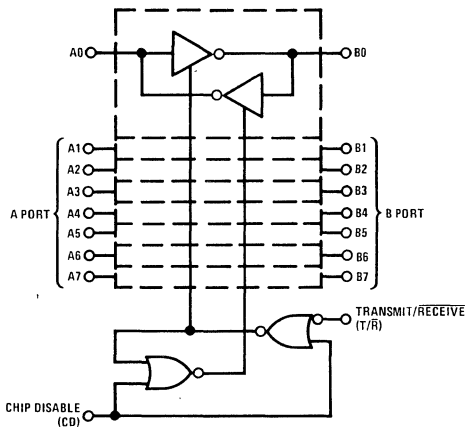


DP7303/DP8303 8-Bit TRI-STATE[®] Bidirectional Transceiver (Inverting)

Features

- 8-bit bidirectional data flow reduces system package count
- Bidirectional TRI-STATE inputs/outputs interface with bus oriented systems
- PNP inputs reduce input loading
- Output high voltage interfaces with TTL, MOS, and CMOS
- 48 mA/300 pF bus drive capability
- Pinouts simplify system interconnections
- Transmit/Receive and chip disable simplify control logic
- Compact 20-pin dual-in-line package
- Bus port glitch free power up/down

Logic and Connection Diagrams



Order Number DP7303J, DP8303J,
or DP8303N
See NS Package J20A or N20A

Logic Table

INPUTS		RESULTING CONDITIONS	
Chip Disable	Transmit/Receive	A Port	B Port
0	0	OUT	IN
0	1	IN	OUT
1	X	TRI-STATE	TRI-STATE

X = Don't care

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1667 mW
Molded Package	1832 mW
Lead Temperature (soldering, 10 seconds)	300°C

*Derate cavity package 11.1 mW/°C above 25°C; derate molded package 14.7 mW/°C.

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})			
DP7303	4.5	5.5	V
DP8303	4.75	5.25	V
Temperature (T _A)			
DP7303	-55	125	°C
DP8303	0	70	°C

DC Electrical Characteristics (Notes 2 and 3)

Parameter		Conditions	Min	Typ	Max	Units	
A Port (A0-A7)							
V _{IH}	Logical "1" Input Voltage	CD = V _{IL} , T/ \bar{R} = 2.0V	2.0			V	
V _{IL}	Logical "0" Input Voltage	CD = V _{IL} , T/ \bar{R} = 2.0V	DP8303		0.8	V	
			DP7303		0.7	V	
V _{OH}	Logical "1" Output Voltage	CD = T/ \bar{R} = V _{IL}	I _{OH} = -0.4 mA	V _{CC} -1.15	V _{CC} -0.7	V	
			I _{OH} = -3 mA	2.7	3.95	V	
V _{OL}	Logical "0" Output Voltage	CD = T/ \bar{R} = V _{IL}	I _{OL} = 16 mA (8303)		0.35	0.5	V
			I _{OL} = 8 mA (both)		0.3	0.4	V
I _{OS}	Output Short Circuit Current	CD = V _{IL} , T/ \bar{R} = V _{IL} , V _O = 0V, V _{CC} = max, Note 4	-10	-38	-75	mA	
I _{IH}	Logical "1" Input Current	CD = V _{IL} , T/ \bar{R} = 2.0V, V _{IH} = 2.7V		0.1	80	μA	
I _I	Input Current at Maximum Input Voltage	CD = 2.0V, V _{CC} = max, V _{IH} = 5.25V			1	mA	
I _{IL}	Logical "0" Input Current	CD = V _{IL} , T/ \bar{R} = 2.0V, V _{IN} = 0.4V		-70	-200	μA	
V _{CLAMP}	Input Clamp Voltage	CD = 2.0V, I _{IN} = -12 mA		-0.7	-1.5	V	
I _{OD}	Output/Input TRI-STATE Current	CD = 2.0V	V _{IN} = 0.4V		-200	μA	
			V _{IN} = 4.0V		80	μA	
B Port (B0-B7)							
V _{IH}	Logical "1" Input Voltage	CD = V _{IL} , T/ \bar{R} = V _{IL}	2.0			V	
V _{IL}	Logical "0" Input Voltage	CD = V _{IL} , T/ \bar{R} = V _{IL}	DP8303		0.8	V	
			DP7303		0.7	V	
V _{OH}	Logical "1" Output Voltage	CD = V _{IL} , T/ \bar{R} = 2.0V	I _{OH} = -0.4 mA	V _{CC} -1.15	V _{CC} -0.8	V	
			I _{OH} = -5 mA	2.7	3.9	V	
			I _{OH} = -10 mA	2.4	3.6	V	
V _{OL}	Logical "0" Output Voltage	CD = V _{IL} , T/ \bar{R} = 2.0V	I _{OL} = 20 mA		0.3	0.4	V
			I _{OL} = 48 mA		0.4	0.5	V
I _{OS}	Output Short Circuit Current	CD = V _{IL} , T/ \bar{R} = 2.0V, V _O = 0V, V _{CC} = max, Note 4	-25	-50	-150	mA	
I _{IH}	Logical "1" Input Current	CD = V _{IL} , T/ \bar{R} = V _{IL} , V _{IH} = 2.7V		0.1	80	μA	
I _I	Input Current at Maximum Input Voltage	CD = 2.0V, V _{CC} = max, V _{IH} = 5.25V			1	mA	
I _{IL}	Logical "0" Input Current	CD = V _{IL} , T/ \bar{R} = V _{IL} , V _{IN} = 0.4V		-70	-200	μA	
V _{CLAMP}	Input Clamp Voltage	CD = 2.0V, I _{IN} = -12 mA		-0.7	-1.5	V	
I _{OD}	Output/Input TRI-STATE Current	CD = 2.0V	V _{IN} = 0.4V		-200	μA	
			V _{IN} = 4.0V		+200	μA	

DC Electrical Characteristics (cont'd.) (Notes 2 and 3)

Parameter	Conditions	Min	Typ	Max	Units
Control Inputs CD, T/R					
V _{IH} Logical "1" Input Voltage		2.0			V
V _{IL} Logical "0" Input Voltage	DP8303			0.8	V
	DP7303			0.7	V
I _{IH} Logical "1" Input Current	V _{IH} = 2.7V		0.5	20	μA
I _I Maximum Input Current	V _{CC} = max, V _{IH} = 5.25V			1.0	mA
I _{IL} Logical "0" Input Current	V _{IL} = 0.4V	T/R	-0.1	-0.25	mA
		CD	-0.25	-0.5	mA
V _{CLAMP} Input Clamp Voltage	I _{IN} = -12 mA		-0.8	-1.5	V
Power Supply Current					
I _{CC} Power Supply Current	CD = 2.0V = V _{IN} , V _{CC} = max		70	100	mA
	CD = 0.4V, V _{INA} = T/R = 2V, V _{CC} = max		100	150	mA

AC Electrical Characteristics V_{CC} = 5V, T_A = 25°C

Parameter	Conditions	Min	Typ	Max	Units
A Port Data/Mode Specifications					
t _{PDHLA} Propagation Delay to a Logical "0" from B Port to A Port	CD = 0.4V, T/R = 0.4V (figure A) R1 = 1k, R2 = 5k, C1 = 30pF		8	12	ns
t _{PDLHA} Propagation Delay to a Logical "1" from B Port to A Port	CD = 0.4V, T/R = 0.4V (figure A) R1 = 1k, R2 = 5k, C1 = 30pF		11	16	ns
t _{PLZA} Propagation Delay from a Logical "0" to TRI-STATE from CD to A Port	B0 to B7 = 2.4V, T/R = 0.4V (figure C) S3 = 1, R5 = 1k, C4 = 15pF		10	15	ns
t _{PHZA} Propagation Delay from a Logical "1" to TRI-STATE from CD to A Port	B0 to B7 = 0.4V, T/R = 0.4V (figure C) S3 = 0, R5 = 1k, C4 = 15pF		8	15	ns
t _{PZLA} Propagation Delay from TRI-STATE to a Logical "0" from CD to A Port	B0 to B7 = 2.4V, T/R = 0.4V (figure C) S3 = 1, R5 = 1k, C4 = 30pF		20	30	ns
t _{PZHA} Propagation Delay from TRI-STATE to a Logical "1" from CD to A Port	B0 to B7 = 0.4V, T/R = 0.4V (figure C) S3 = 0, R5 = 5k, C4 = 30pF		19	30	ns
B Port Data/Mode Specifications					
t _{PDHLB} Propagation Delay to a Logical "0" from A Port to B Port	CD = 0.4V, T/R = 2.4V (figure A) R1 = 100Ω, R2 = 1k, C1 = 300pF R1 = 667Ω, R2 = 5k, C1 = 45pF		12	18	ns
			7	12	ns
t _{PDLHB} Propagation Delay to a Logical "1" from A Port to B Port	CD = 0.4V, T/R = 2.4V (figure A) R1 = 100Ω, R2 = 1k, C1 = 300pF R1 = 667Ω, R2 = 5k, C1 = 45pF		15	20	ns
			9	14	ns
t _{PLZB} Propagation Delay from a Logical "0" to TRI-STATE from CD to B Port	A0 to A7 = 2.4V, T/R = 2.4V (figure C) S3 = 1, R5 = 1k, C4 = 15pF		13	18	ns
t _{PHZB} Propagation Delay from a Logical "1" to TRI-STATE from CD to B Port	A0 to A7 = 0.4V, T/R = 2.4V (figure C) S3 = 0, R5 = 1k, C4 = 15pF		8	15	ns
t _{PZLB} Propagation Delay from TRI-STATE to a Logical "0" from CD to B Port	A0 to A7 = 2.4V, T/R = 2.4V (figure C) S3 = 1, R5 = 100Ω, C4 = 300pF S3 = 1, R5 = 667Ω, C4 = 45pF		25	35	ns
			16	25	ns
t _{PZHB} Propagation Delay from TRI-STATE to a Logical "1" from CD to B Port	A0 to A7 = 0.4V, T/R = 2.4V (figure C) S3 = 0, R5 = 1k, C4 = 300pF S3 = 0, R5 = 5k, C4 = 45pF		22	35	ns
			14	25	ns

AC Electrical Characteristics (cont'd) $V_{CC} = 5V, T_A = 25^\circ C$

Parameter	Conditions	Min	Typ	Max	Units
Transmit/Receive Mode Specifications					
t _{TRL}	Propagation Delay from Transmit Mode to Receive a Logical "0," T/R to A Port CD = 0.4 V (figure B) S1 = 1, R4 = 100 Ω, C3 = 5 pF S2 = 1, R3 = 1k, C2 = 30 pF		23	35	ns
t _{TRH}	Propagation Delay from Transmit Mode to Receive a Logical "1," T/R to A Port CD = 0.4 V (figure B) S1 = 0, R4 = 100 Ω, C3 = 5 pF S2 = 0, R3 = 5k, C2 = 30 pF		22	35	ns
t _{RTL}	Propagation Delay from Receive Mode to Transmit a Logical "0," T/R to B Port CD = 0.4 V (figure B) S1 = 1, R4 = 100 Ω, C3 = 300 pF S2 = 1, R3 = 300 Ω, C2 = 5 pF		26	35	ns
t _{RTH}	Propagation Delay from Receive Mode to Transmit a Logical "1," T/R to B Port CD = 0.4 V (figure B) S1 = 0, R4 = 1k, C3 = 300 pF S2 = 0, R3 = 300 Ω, C2 = 5 pF		27	35	ns

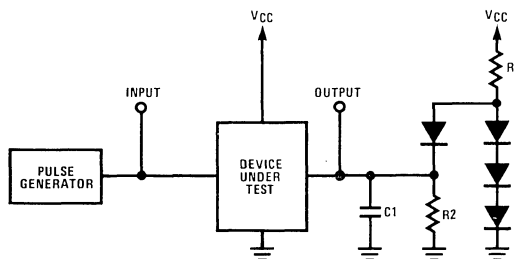
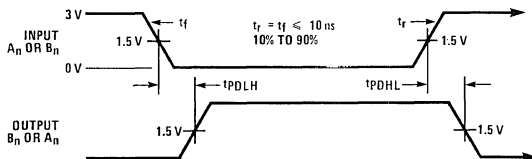
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the supply and temperature range listed in the table of Recommended Operating Conditions. All typical values given are for $V_{CC} = 5V$ and $T_A = 25^\circ C$.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

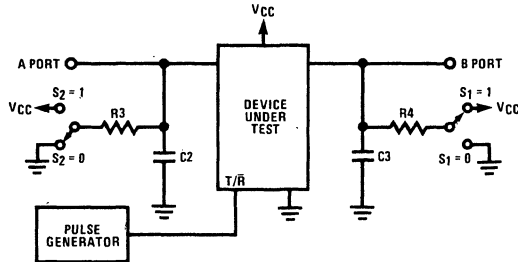
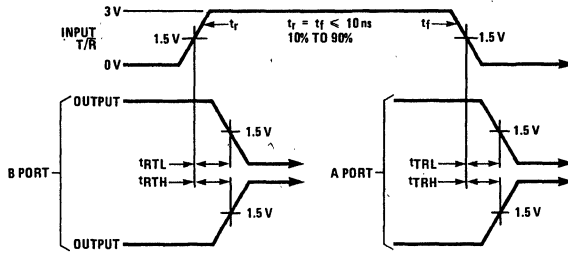
Switching Time Waveforms and AC Test Circuits



NOTE: C1 INCLUDES TEST FIXTURE CAPACITANCE.

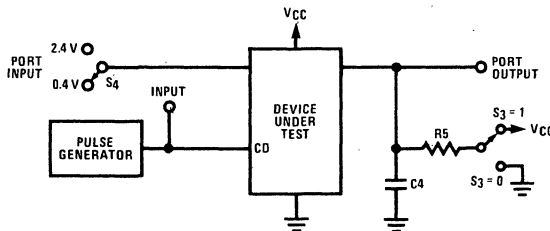
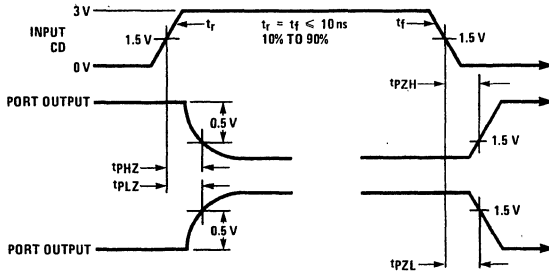
FIGURE A. Propagation Delay from A Port to B Port or from B Port to A Port

Switching Time Waveforms and AC Test Circuits (cont'd.)



NOTE: C2 AND C3 INCLUDE TEST FIXTURE CAPACITANCE.

FIGURE B. Propagation Delay from T/R to A Port or B Port



NOTE: C4 INCLUDES TEST FIXTURE CAPACITANCE. PORT INPUT IS IN A FIXED LOGICAL CONDITION. SEE AC TABLE.

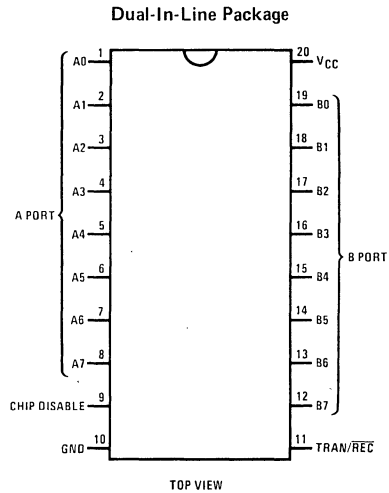
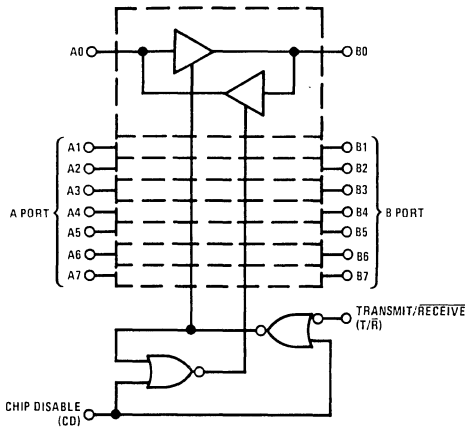
FIGURE C. Propagation Delay to/from TRI-STATE® from CD to A Port or B Port

DP7304B/DP8304B 8-Bit TRI-STATE[®] Bidirectional Transceiver (Non-Inverting)

Features

- 8-bit bidirectional data flow reduces system package count
- Bidirectional TRI-STATE inputs/outputs interface with bus oriented systems
- PNP inputs reduce input loading
- Output high voltage interfaces with TTL, MOS, and CMOS
- 48 mA/300 pF bus drive capability
- Pinouts simplify system interconnections
- Transmit/Receive and chip disable simplify control logic
- Compact 20-pin dual-in-line package
- Bus port glitch free power up/down

Logic and Connection Diagrams



Order Number DP7304BJ, DP8304BJ,
or DP8304BN
See NS Package J20A or N20A

Logic Table

INPUTS		RESULTING CONDITIONS	
Chip Disable	Transmit/Receive	A Port	B Port
0	0	OUT	IN
0	1	IN	OUT
1	X	TRI-STATE	TRI-STATE

X = Don't care

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1667 mW
Molded Package	1832 mW
Lead Temperature (soldering, 10 seconds)	300°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})			
DP7304B	4.5	5.5	V
DP8304B	4.75	5.25	V
Temperature (T _A)			
DP7304B	-55	125	°C
DP8304B	0	70	°C

*Derate cavity package 11.1 mW/°C above 25°C; derate molded package 14.7 mW/°C above 25°C.

DC Electrical Characteristics (Notes 2 and 3)

Parameter		Conditions	Min	Typ	Max	Units	
A Port (A0-A7)							
V _{IH}	Logical "1" Input Voltage	CD = V _{IL} , T/ \bar{R} = 2.0V	2.0			V	
V _{IL}	Logical "0" Input Voltage	CD = V _{IL} , T/ \bar{R} = 2.0V	DP8304B		0.8	V	
			DP7304B		0.7	V	
V _{OH}	Logical "1" Output Voltage	CD = V _{IL} , T/ \bar{R} = V _{IL}	I _{OH} = -0.4 mA	V _{CC} -1.15	V _{CC} -0.7	V	
			I _{OH} = -3mA	2.7	3.95	V	
V _{OL}	Logical "0" Output Voltage	CD = T/ \bar{R} = V _{IL}	I _{OL} = 16 mA (8304B)		0.35	0.5	V
			I _{OL} = 8 mA (both)		0.3	0.4	V
I _{OS}	Output Short Circuit Current	CD = V _{IL} , T/ \bar{R} = V _{IL} , V _O = 0V, V _{CC} = max, Note 4	-10	-38	-75	mA	
I _{IH}	Logical "1" Input Current	CD = V _{IL} , T/ \bar{R} = 2.0V, V _{IH} = 2.7V		0.1	80	μA	
I _I	Input Current at Maximum Input Voltage	CD = 2.0V, V _{CC} = max, V _{IH} = 5.25V			1	mA	
I _{IL}	Logical "0" Input Current	CD = V _{IL} , T/ \bar{R} = 2.0V, V _{IN} = 0.4V		-70	-200	μA	
V _{CLAMP}	Input Clamp Voltage	CD = 2.0V, I _{IN} = -12 mA		-0.7	-1.5	V	
I _{OD}	Output/Input TRI-STATE Current	CD = 2.0V	V _{IN} = 0.4V		-200	μA	
			V _{IN} = 4.0V		80	μA	
B Port (B0-B7)							
V _{IH}	Logical "1" Input Voltage	CD = V _{IL} , T/ \bar{R} = V _{IL}	2.0			V	
V _{IL}	Logical "0" Input Voltage	CD = V _{IL} , T/ \bar{R} = V _{IL}	DP8304B		0.8	V	
			DP7304B		0.7	V	
V _{OH}	Logical "1" Output Voltage	CD = V _{IL} , T/ \bar{R} = 2.0V	I _{OH} = -0.4 mA	V _{CC} -1.15	V _{CC} -0.8	V	
			I _{OH} = -5 mA	2.7	3.9	V	
			I _{OH} = -10 mA	2.4	3.6	V	
V _{OL}	Logical "0" Output Voltage	CD = V _{IL} , T/ \bar{R} = 2.0V	I _{OL} = 20 mA		0.3	0.4	V
			I _{OL} = 48 mA		0.4	0.5	V
I _{OS}	Output Short Circuit Current	CD = V _{IL} , T/ \bar{R} = 2.0V, V _O = 0V, V _{CC} = max, Note 4	-25	-50	-150	mA	
I _{IH}	Logical "1" Input Current	CD = V _{IL} , T/ \bar{R} = V _{IL} , V _{IH} = 2.7V		0.1	80	μA	
I _I	Input Current at Maximum Input Voltage	CD = 2.0V, V _{CC} = max, V _{IH} = 5.25V			1	mA	
I _{IL}	Logical "0" Input Current	CD = V _{IL} , T/ \bar{R} = V _{IL} , V _{IN} = 0.4V		-70	-200	μA	
V _{CLAMP}	Input Clamp Voltage	CD = 2.0V, I _{IN} = -12 mA		-0.7	-1.5	V	
I _{OD}	Output/Input TRI-STATE Current	CD = 2.0V	V _{IN} = 0.4V		-200	μA	
			V _{IN} = 4.0V		+200	μA	

DC Electrical Characteristics (cont'd.) (Notes 2 and 3)

Parameter	Conditions	Min	Typ	Max	Units	
Control Inputs CD, T/ \bar{R}						
V _{IH}	Logical "1" Input Voltage	2.0			V	
V _{IL}	Logical "0" Input Voltage	DP8304B		0.8	V	
		DP7304B		0.7	V	
I _{IH}	Logical "1" Input Current	V _{IH} = 2.7V	0.5	20	μ A	
I _I	Maximum Input Current	V _{CC} = max, V _{IH} = 5.25V		1.0	mA	
I _{IL}	Logical "0" Input Current	V _{IL} = 0.4V	T/ \bar{R}	-0.1	-0.25	mA
			CD	-0.25	-0.5	mA
V _{CLAMP}	Input Clamp Voltage	I _{IN} = -12 mA	-0.8	-1.5	V	
Power Supply Current						
I _{CC}	Power Supply Current	CD = 2.0V, V _{IN} = 0.4V, V _{CC} = max	70	100	mA	
		CD = V _{INA} = 0.4V, T/ \bar{R} = 2V, V _{CC} = max	90	140	mA	

AC Electrical Characteristics V_{CC} = 5V, T_A = 25°C

Parameter	Conditions	Min	Typ	Max	Units	
A Port Data/Mode Specifications						
t _{PDHLA}	Propagation Delay to a Logical "0" from B Port to A Port	CD = 0.4V, T/ \bar{R} = 0.4V (figure A), R1 = 1k, R2 = 5k, C1 = 30 pF		14	18	ns
t _{PDLHA}	Propagation Delay to a Logical "1" from B Port to A Port	CD = 0.4V, T/ \bar{R} = 0.4V (figure A), R1 = 1k, R2 = 5k, C1 = 30 pF		13	18	ns
t _{PLZA}	Propagation Delay from a Logical "0" to TRI-STATE from CD to A Port	B0 to B7 = 0.4V, T/ \bar{R} = 0.4V (figure C) S3 = 1, R5 = 1k, C4 = 15 pF		11	15	ns
t _{PHZA}	Propagation Delay from a Logical "1" to TRI-STATE from CD to A Port	B0 to B7 = 2.4V, T/ \bar{R} = 0.4V (figure C) S3 = 0, R5 = 1k, C4 = 15 pF		8	15	ns
t _{PZLA}	Propagation Delay from TRI-STATE to a Logical "0" from CD to A Port	B0 to B7 = 0.4V, T/ \bar{R} = 0.4V (figure C) S3 = 1, R5 = 1k, C4 = 30 pF		27	35	ns
t _{PZHA}	Propagation Delay from TRI-STATE to a Logical "1" from CD to A Port	B0 to B7 = 2.4V, T/ \bar{R} = 0.4V (figure C) S3 = 0, R5 = 5k, C4 = 30 pF		19	25	ns
B Port Data/Mode Specifications						
t _{PDHLB}	Propagation Delay to a Logical "0" from A Port to B Port	CD = 0.4V, T/ \bar{R} = 2.4V (figure A) R1 = 100 Ω , R2 = 1k, C1 = 300 pF R1 = 667 Ω , R2 = 5k, C1 = 45 pF		18	23	ns
				11	18	ns
t _{PDLHB}	Propagation Delay to a Logical "1" from A Port to B Port	CD = 0.4V, T/ \bar{R} = 2.4V (figure A) R1 = 100 Ω , R2 = 1k, C1 = 300 pF R1 = 667 Ω , R2 = 5k, C1 = 45 pF		16	23	ns
				11	18	ns
t _{PLZB}	Propagation Delay from a Logical "0" to TRI-STATE from CD to B Port	A0 to A7 = 0.4V, T/ \bar{R} = 2.4V (figure C) S3 = 1, R5 = 1k, C4 = 15 pF		13	18	ns
t _{PHZB}	Propagation Delay from a Logical "1" to TRI-STATE from CD to B Port	A0 to A7 = 2.4V, T/ \bar{R} = 2.4V (figure C) S3 = 0, R5 = 1k, C4 = 15 pF		8	15	ns
t _{PZLB}	Propagation Delay from TRI-STATE to a Logical "0" from CD to B Port	A0 to A7 = 0.4V, T/ \bar{R} = 2.4V (figure C) S3 = 1, R5 = 100 Ω , C4 = 300 pF S3 = 1, R5 = 667 Ω , C4 = 45 pF		32	40	ns
				16	22	ns
t _{PZHB}	Propagation Delay from TRI-STATE to a Logical "1" from CD to B Port	A0 to A7 = 2.4V, T/ \bar{R} = 2.4V (figure C) S3 = 0, R5 = 1k, C4 = 300 pF S3 = 0, R5 = 5k, C4 = 45 pF		26	35	ns
				14	22	ns

AC Electrical Characteristics (cont'd.) $V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$

Parameter	Conditions	Min	Typ	Max	Units
Transmit/Receive Mode Specifications					
t_{TRL}	Propagation Delay from Transmit Mode to Receive a Logical "0," T/ \bar{R} to A Port CD = 0.4 V (figure B) S1 = 0, R4 = 100 Ω , C3 = 5 pF S2 = 1, R3 = 1k, C2 = 30 pF		30	40	ns
t_{TRH}	Propagation Delay from Transmit Mode to Receive a Logical "1," T/ \bar{R} to A Port CD = 0.4 V (figure B) S1 = 1, R4 = 100 Ω , C3 = 5 pF S2 = 0, R3 = 5k, C2 = 30 pF		28	40	ns
t_{RTL}	Propagation Delay from Receive Mode to Transmit a Logical "0," T/ \bar{R} to B Port CD = 0.4 V (figure B) S1 = 1, R4 = 100 Ω , C3 = 300 pF S2 = 0, R3 = 300 Ω , C2 = 5 pF		31	40	ns
t_{RTH}	Propagation Delay from Receive Mode to Transmit a Logical "1," T/ \bar{R} to B Port CD = 0.4 V (figure B) S1 = 0, R4 = 1k, C3 = 300 pF S2 = 1, R3 = 300 Ω , C2 = 5 pF		28	40	ns

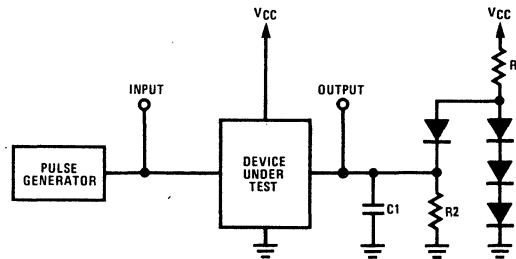
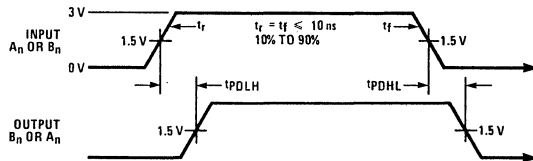
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the supply and temperature range listed in the table of Recommended Operating Conditions. All typical values given are for $V_{CC} = 5\text{ V}$ and $T_A = 25^\circ\text{C}$.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

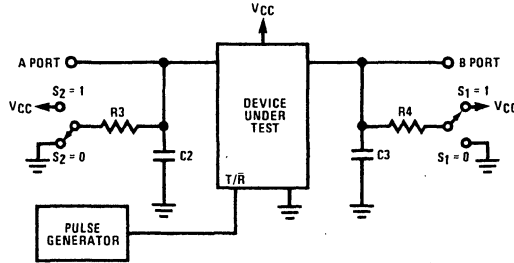
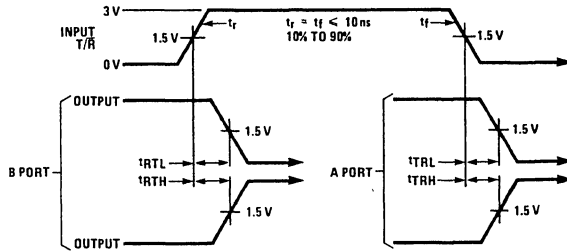
Switching Time Waveforms and AC Test Circuits



NOTE: C1 INCLUDES TEST FIXTURE CAPACITANCE.

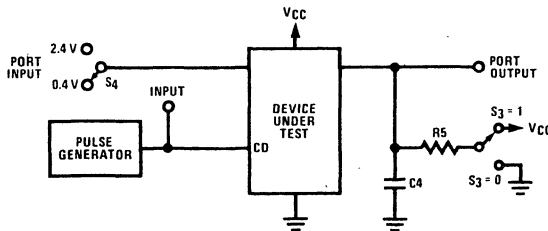
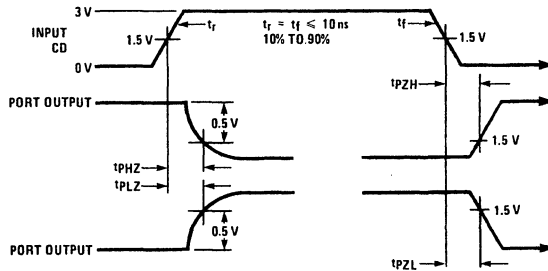
FIGURE A. Propagation Delay from A Port to B Port or from B Port to A Port

Switching Time Waveforms and AC Test Circuits (cont'd.)



NOTE: C2 AND C3 INCLUDE TEST FIXTURE CAPACITANCE.

FIGURE B. Propagation Delay from T/R to A Port or B Port



NOTE: C4 INCLUDES TEST FIXTURE CAPACITANCE. PORT INPUT IS IN A FIXED LOGICAL CONDITION. SEE AC TABLE.

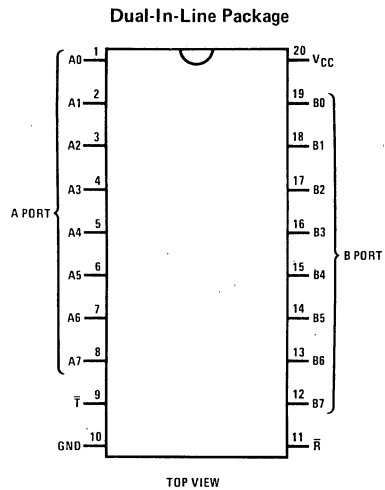
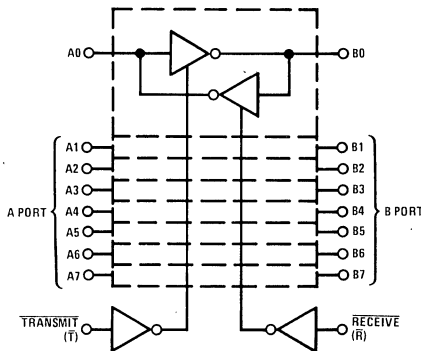
FIGURE C. Propagation Delay to/from TRI-STATE® from CD to A Port or B Port

DP7307/DP8307 8-Bit TRI-STATE[®] Bidirectional Transceiver (Inverting)

Features

- 8-bit bidirectional data flow reduces system package count
- Bidirectional TRI-STATE inputs/outputs interface with bus oriented systems
- PNP inputs reduce input loading
- Output high voltage interfaces with TTL, MOS, and CMOS
- 48 mA/300 pF bus drive capability
- Pinouts simplify system interconnections
- Independent \bar{T} and \bar{R} controls for versatility
- Compact 20-pin dual-in-line package
- Bus port glitch free power up/down

Logic and Connection Diagrams



**Order Number DP7307J, DP8307J
or DP8307N
See NS Package J20A or N20A**

Logic Table

CONTROL INPUTS		RESULTING CONDITIONS	
Transmit	Receive	A Port	B Port
1	0	OUT	IN
0	1	IN	OUT
1	1	TRI-STATE	TRI-STATE
0	0	Both Active*	

*This is not an intended logic condition and may cause oscillations.

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1667 mW
Molded Package	1832 mW
Lead Temperature (soldering, 10 seconds)	300°C

*Derate cavity package 11.1 mW/°C above 25°C; derate molded package 14.7 mW/°C above 25°C.

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})			
DP7307	4.5	5.5	V
DP8307	4.75	5.25	V
Temperature (T _A)			
DP7307	-55	125	°C
DP8307	0	70	°C

DC Electrical Characteristics (Notes 2 and 3)

Parameter	Conditions	Min	Typ	Max	Units
A Port (A0-A7)					
V _{IH}	Logical "1" Input Voltage	$\bar{T} = V_{IL}, \bar{R} = 2.0V$		2.0	V
V _{IL}	Logical "0" Input Voltage		$\bar{T} = V_{IL}, \bar{R} = 2.0V$	DP8307	0.8
				DP7307	0.7
V _{OH}	Logical "1" Output Voltage	$\bar{T} = 2.0V, \bar{R} = V_{IL}$	I _{OH} = -0.4 mA	V _{CC} -1.15	V _{CC} -0.7
			I _{OH} = -3 mA	2.7	3.95
V _{OL}	Logical "0" Output Voltage	$\bar{T} = 2.0V, \bar{R} = V_{IL}$	I _{OL} = 16 mA (8307)	0.35	0.5
			I _{OL} = 8 mA (both)	0.3	0.4
I _{OS}	Output Short Circuit Current	$\bar{T} = 2.0V, \bar{R} = V_{IL}, V_O = 0V, V_{CC} = \text{max, Note 4}$		-10	-38
I _{IH}	Logical "1" Input Current	$\bar{T} = V_{IL}, \bar{R} = 2.0V, V_{IH} = 2.7V$		0.1	80
I _I	Input Current at Maximum Input Voltage	$\bar{T} = \bar{R} = 2.0V, V_{CC} = \text{max}, V_{IH} = 5.25V$			1
I _{IL}	Logical "0" Input Current	$\bar{T} = V_{IL}, \bar{R} = 2.0V, V_{IN} = 0.4V$		-70	-200
V _{CLAMP}	Input Clamp Voltage	$\bar{T} = \bar{R} = 2.0V, I_{IN} = -12 \text{ mA}$		-0.7	-1.5
I _{OD}	Output/Input TRI-STATE Current	$\bar{T} = \bar{R} = 2.0V$		V _{IN} = 0.4V	-200
				V _{IN} = 4.0V	80
B Port (B0-B7)					
V _{IH}	Logical "1" Input Voltage	$\bar{T} = 2.0V, \bar{R} = V_{IL}$		2.0	V
V _{IL}	Logical "0" Input Voltage		$\bar{T} = 2.0V, \bar{R} = V_{IL}$	DP8307	0.8
				DP7307	0.7
V _{OH}	Logical "1" Output Voltage	$\bar{T} = V_{IL}, \bar{R} = 2.0V$	I _{OH} = -0.4 mA	V _{CC} -1.15	V _{CC} -0.8
			I _{OH} = -5 mA	2.7	3.9
			I _{OH} = -10 mA	2.4	3.6
V _{OL}	Logical "0" Output Voltage	$\bar{T} = V_{IL}, \bar{R} = 2.0V$	I _{OL} = 20 mA	0.3	0.4
			I _{OL} = 48 mA	0.4	0.5
I _{OS}	Output Short Circuit Current	$\bar{T} = V_{IL}, \bar{R} = 2.0V, V_O = 0V, V_{CC} = \text{max, Note 4}$		-25	-50
I _{IH}	Logical "1" Input Current	$\bar{T} = 2.0V, \bar{R} = V_{IL}, V_{IH} = 2.7V$		0.1	80
I _I	Input Current at Maximum Input Voltage	$\bar{T} = \bar{R} = 2.0V, V_{CC} = \text{max}, V_{IH} = 5.25V$			1
I _{IL}	Logical "0" Input Current	$\bar{T} = 2.0V, \bar{R} = V_{IL}, V_{IL} = 0.4V$		-70	-200
V _{CLAMP}	Input Clamp Voltage	$\bar{T} = \bar{R} = 2.0V, I_{IN} = -12 \text{ mA}$		-0.7	-1.5
I _{OD}	Output/Input TRI-STATE Current	$\bar{T} = \bar{R} = 2.0V$		V _{IN} = 0.4V	-200
				V _{IN} = 4.0V	+200

DC Electrical Characteristics (cont'd.) (Notes 2 and 3)

Parameter	Conditions	Min	Typ	Max	Units	
Control Inputs \bar{T} , \bar{R}						
V_{IH} Logical "1" Input Voltage		2.0			V	
V_{IL} Logical "0" Input Voltage	DP8307			0.8	V	
	DP7307			0.7	V	
I_{IH} Logical "1" Input Current	$V_{IH} = 2.7V$		0.5	20	μA	
I_I Maximum Input Current	$V_{CC} = \text{max}, V_{IH} = 5.25V$			1.0	mA	
I_{IL} Logical "0" Input Current	$V_{IL} = 0.4V$	\bar{R}		-0.1	-0.25	mA
		\bar{T}		-0.25	-0.5	mA
V_{CLAMP} Input Clamp Voltage	$I_{IN} = -12mA$		-0.8	-1.5	V	
Power Supply Current						
I_{CC} Power Supply Current	$\bar{T} = \bar{R} = 2.0V, V_{IN} = 2.0V, V_{CC} = \text{max}$		70	100	mA	
	$\bar{T} = 0.4V, V_{INA} = \bar{R} = 2V, V_{CC} = \text{max}$		100	150	mA	

AC Electrical Characteristics $V_{CC} = 5V, T_A = 25^\circ C$

Parameter	Conditions	Min	Typ	Max	Units
A Port Data/Mode Specifications					
t_{PDHLA} Propagation Delay to a Logical "0" from B Port to A Port	$\bar{T} = 2.4V, \bar{R} = 0.4V$ (figure A) $R1 = 1k, R2 = 5k, C1 = 30pF$		8	12	ns
t_{PDLHA} Propagation Delay to a Logical "1" from B Port to A Port	$\bar{T} = 2.4V, \bar{R} = 0.4V$ (figure A) $R1 = 1k, R2 = 5k, C1 = 30pF$		11	16	ns
t_{PLZA} Propagation Delay from a Logical "0" to TRI-STATE from \bar{R} to A Port	$B0$ to $B7 = 2.4V, \bar{T} = 2.4V$ (figure B) $S3 = 1, R5 = 1k, C4 = 15pF$		10	15	ns
t_{PHZA} Propagation Delay from a Logical "1" to TRI-STATE from \bar{R} to A Port	$B0$ to $B7 = 0.4V, \bar{T} = 2.4V$ (figure B) $S3 = 0, R5 = 1k, C4 = 15pF$		8	15	ns
t_{PZLA} Propagation Delay from TRI-STATE to a Logical "0" from \bar{R} to A Port	$B0$ to $B7 = 2.4V, \bar{T} = 2.4V$ (figure B) $S3 = 1, R5 = 1k, C4 = 30pF$		25	35	ns
t_{PZHA} Propagation Delay from TRI-STATE to a Logical "1" from \bar{R} to A Port	$B0$ to $B7 = 0.4V, \bar{T} = 2.4V$ (figure B) $S3 = 0, R5 = 5k, C4 = 30pF$		24	35	ns
B Port Data/Mode Specifications					
t_{PDHLB} Propagation Delay to a Logical "0" from A Port to B Port	$\bar{T} = 0.4V, \bar{R} = 2.4V$ (figure A) $R1 = 100\Omega, R2 = 1k, C1 = 300pF$ $R1 = 667\Omega, R2 = 5k, C1 = 45pF$		12	18	ns
			8	12	ns
t_{PDLHB} Propagation Delay to a Logical "1" from A Port to B Port	$\bar{T} = 0.4V, \bar{R} = 2.4V$ (figure A) $R1 = 100\Omega, R2 = 1k, C1 = 300pF$ $R1 = 667\Omega, R2 = 5k, C1 = 45pF$		15	23	ns
			9	14	ns
t_{PLZB} Propagation Delay from a Logical "0" to TRI-STATE from \bar{T} to B Port	$A0$ to $A7 = 2.4V, \bar{R} = 2.4V$ (figure B) $S3 = 1, R5 = 1k, C4 = 15pF$		13	18	ns
t_{PHZB} Propagation Delay from a Logical "1" to TRI-STATE from \bar{T} to B Port	$A0$ to $A7 = 0.4V, \bar{R} = 2.4V$ (figure B) $S3 = 0, R5 = 1k, C4 = 15pF$		8	15	ns
t_{PZLB} Propagation Delay from TRI-STATE to a Logical "0" from \bar{T} to B Port	$A0$ to $A7 = 2.4V, \bar{R} = 2.4V$ (figure B) $S3 = 1, R5 = 100\Omega, C4 = 300pF$ $S3 = 1, R5 = 667\Omega, C4 = 45pF$		32	40	ns
			18	25	ns
t_{PZHB} Propagation Delay from TRI-STATE to a Logical "1" from \bar{T} to B Port	$A0$ to $A7 = 0.4V, \bar{R} = 2.4V$ (figure B) $S3 = 0, R5 = 1k, C4 = 300pF$ $S3 = 0, R5 = 5k, C4 = 45pF$		25	35	ns
			16	25	ns

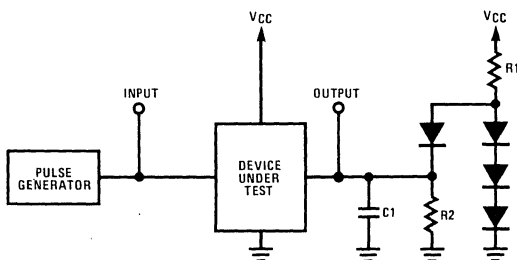
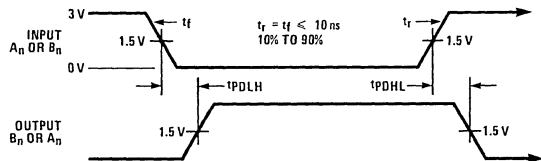
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the supply and temperature range listed in the table of Recommended Operating Conditions. All typical values given are for $V_{CC} = 5V$ and $T_A = 25^\circ C$.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

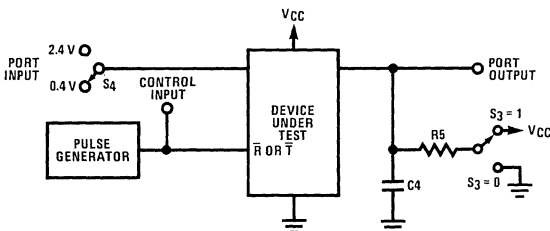
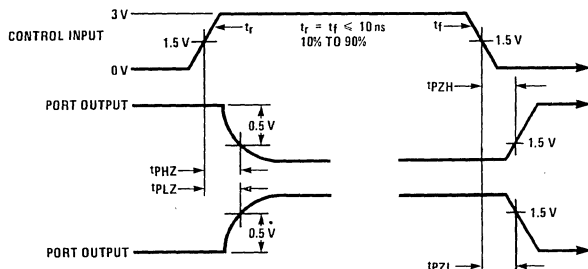
Note 4: Only one output at a time should be shorted.

Switching Time Waveforms and AC Test Circuits



NOTE: C1 INCLUDES TEST FIXTURE CAPACITANCE.

FIGURE A. Propagation Delay from A port to B port or from B port to A port



NOTE: C4 INCLUDES TEST FIXTURE CAPACITANCE. PORT INPUT IS IN A FIXED LOGICAL CONDITION. SEE AC TABLE.

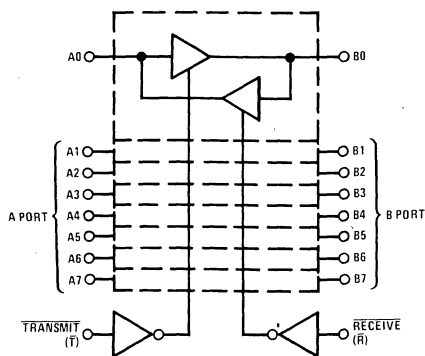
Figure B. Propagation Delay to/from TRI-STATE from \bar{R} to A Port and \bar{T} to B Port

DP7308/DP8308 8-Bit TRI-STATE® Bidirectional Transceiver (Non-Inverting)

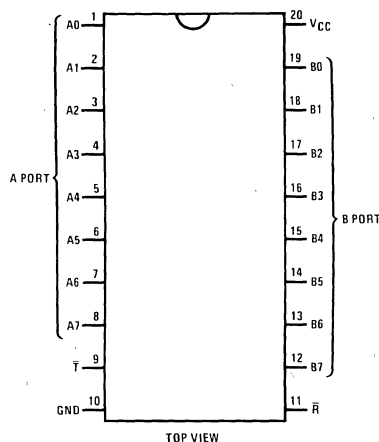
Features

- 8-bit bidirectional data flow reduces system package count
- Bidirectional TRI-STATE inputs/outputs interface with bus oriented systems
- PNP inputs reduce input loading
- Output high voltage interfaces with TTL, MOS, and CMOS
- 48 mA/300 pF bus drive capability
- Pinouts simplify system interconnections
- Independent \bar{T} and \bar{R} controls for versatility
- Compact 20-pin dual-in-line package
- Bus port glitch free power up/down

Logic and Connection Diagrams



Dual-In-Line Package



Order Number DP7308J, DP8308J
or DP8308N
See NS Package J20A or N20A

Logic Table

CONTROL INPUTS		RESULTING CONDITIONS	
\bar{T}	\bar{R}	A Port	B Port
1	0	OUT	IN
0	1	IN	OUT
1	1	TRI-STATE	TRI-STATE
0	0	Both Active*	

*This is not an intended logic condition and may cause oscillations.

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1667 mW
Molded Package	1832 mW
Lead Temperature (soldering, 10 seconds)	300°C

*Derate cavity package 11.1 mW/°C above 25°C; derate molded package 14.7 mW/°C above 25°C.

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})			
DP7308	4.5	5.5	V
DP8308	4.75	5.25	V
Temperature (T _A)			
DP7308	-55	125	°C
DP8308	0	70	°C

DC Electrical Characteristics (Notes 2 and 3)

Parameter	Conditions	Min	Typ	Max	Units
A Port (A0-A7)					
V _{IH}	Logical "1" Input Voltage	$\bar{T} = V_{IL}, \bar{R} = 2.0V$	2.0		V
V _{IL}	Logical "0" Input Voltage	$\bar{T} = V_{IL}, \bar{R} = 2.0V$			
		DP8308		0.8	V
		DP7308		0.7	V
V _{OH}	Logical "1" Output Voltage	$\bar{T} = 2.0V, \bar{R} = V_{IL}$			
		I _{OH} = -0.4 mA	V _{CC} -1.15	V _{CC} -0.7	V
		I _{OH} = -3 mA	2.7	3.95	V
V _{OL}	Logical "0" Output Voltage	$\bar{T} = 2.0V, \bar{R} = V_{IL}$			
		I _{OL} = 16 mA (8308)		0.35	0.5
		I _{OL} = 8 mA (both)		0.3	0.4
I _{OS}	Output Short Circuit Current	$\bar{T} = 2.0V, \bar{R} = V_{IL}, V_O = 0V, V_{CC} = \text{max, Note 4}$	-10	-38	-75
I _{IH}	Logical "1" Input Current	$\bar{T} = V_{IL}, \bar{R} = 2.0V, V_{IH} = 2.7V$		0.1	80
I _I	Input Current at Maximum Input Voltage	$\bar{R} = \bar{T} = 2.0V, V_{CC} = \text{max}, V_{IH} = 5.25V$			1
I _{IL}	Logical "0" Input Current	$\bar{T} = V_{IL}, \bar{R} = 2.0V, V_{IN} = 0.4V$		-70	-200
V _{CLAMP}	Input Clamp Voltage	$\bar{T} = \bar{R} = 2.0V, I_{IN} = -12 \text{ mA}$		-0.7	-1.5
I _{OD}	Output/Input TRI-STATE Current	$\bar{T} = \bar{R} = 2.0V$			
		V _{IN} = 0.4V			-200
		V _{IN} = 4.0V			80
B Port (B0-B7)					
V _{IH}	Logical "1" Input Voltage	$\bar{T} = 2.0V, \bar{R} = V_{IL}$	2.0		V
V _{IL}	Logical "0" Input Voltage	$\bar{T} = 2.0V, \bar{R} = V_{IL}$			
		DP8308		0.8	V
		DP7308		0.7	V
V _{OH}	Logical "1" Output Voltage	$\bar{T} = V_{IL}, \bar{R} = 2.0V$			
		I _{OH} = -0.4 mA	V _{CC} -1.15	V _{CC} -0.8	V
		I _{OH} = -5 mA	2.7	3.9	V
		I _{OH} = -10 mA	2.4	3.6	V
V _{OL}	Logical "0" Output Voltage	$\bar{T} = V_{IL}, \bar{R} = 2.0V$			
		I _{OL} = 20 mA		0.3	0.4
		I _{OL} = 48 mA		0.4	0.5
I _{OS}	Output Short Circuit Current	$\bar{T} = V_{IL}, \bar{R} = 2.0V, V_O = 0V, V_{CC} = \text{max, Note 4}$	-25	-50	-150
I _{IH}	Logical "1" Input Current	$\bar{T} = 2.0V, \bar{R} = V_{IL}, V_{IH} = 2.7V$		0.1	80
I _I	Input Current at Maximum Input Voltage	$\bar{T} = \bar{R} = 2.0V, V_{CC} = \text{max}, V_{IH} = 5.25V$			1
I _{IL}	Logical "0" Input Current	$\bar{T} = 2.0V, \bar{R} = V_{IL}, V_{IN} = 0.4V$		-70	-200
V _{CLAMP}	Input Clamp Voltage	$\bar{T} = \bar{R} = 2.0V, I_{IN} = -12 \text{ mA}$		-0.7	-1.5
I _{OD}	Output/Input TRI-STATE Current	$\bar{T} = \bar{R} = 2.0V$			
		V _{IN} = 0.4V			-200
		V _{IN} = 4.0V			+200

DC Electrical Characteristics (cont'd.) (Notes 2 and 3)

Parameter	Conditions	Min	Typ	Max	Units	
Control Inputs \bar{T} , \bar{R}						
V_{IH} Logical "1" Input Voltage		2.0			V	
V_{IL} Logical "0" Input Voltage	DP8308			0.8	V	
	DP7308			0.7	V	
I_{IH} Logical "1" Input Current	$V_{IH} = 2.7V$		0.5	20	μA	
I_I Maximum Input Current	$V_{CC} = \text{max}, V_{IH} = 5.25V$			1.0	mA	
I_{IL} Logical "0" Input Current	$V_{IL} = 0.4V$	\bar{R}		-0.1	-0.25	mA
		\bar{T}		-0.25	-0.5	mA
V_{CLAMP} Input Clamp Voltage	$I_{IN} = -12mA$		-0.8	-1.5	V	
Power Supply Current						
I_{CC} Power Supply Current	$\bar{T} = \bar{R} = 2.0V, V_{IN} = 0.4V, V_{CC} = \text{max}$		70	100	mA	
	$\bar{T} = V_{INA} = 0.4V, \bar{R} = 2V, V_{CC} = \text{max}$		90	140	mA	

AC Electrical Characteristics $V_{CC} = 5V, T_A = 25^\circ C$

Parameter	Conditions	Min	Typ	Max	Units
A Port Data/Mode Specifications					
t_{PDHLA} Propagation Delay to a Logical "0" from B Port to A Port	$\bar{T} = 2.4V, \bar{R} = 0.4V$ (figure A) $R1 = 1k, R2 = 5k, C1 = 30pF$		14	18	ns
t_{PDLHA} Propagation Delay to a Logical "1" from B Port to A Port	$\bar{T} = 2.4V, \bar{R} = 0.4V$ (figure A) $R1 = 1k, R2 = 5k, C1 = 30pF$		13	18	ns
t_{PLZA} Propagation Delay from a Logical "0" to TRI-STATE from \bar{R} to A Port	$B0 \text{ to } B7 = 0.4V, \bar{T} = 2.4V$ (figure B) $S3 = 1, R5 = 1k, C4 = 15pF$		11	15	ns
t_{PHZA} Propagation Delay from a Logical "1" to TRI-STATE from \bar{R} to A Port	$B0 \text{ to } B7 = 2.4V, \bar{T} = 2.4V$ (figure B) $S3 = 0, R5 = 1k, C4 = 15pF$		8	15	ns
t_{PZLA} Propagation Delay from TRI-STATE to a Logical "0" from \bar{R} to A Port	$B0 \text{ to } B7 = 0.4V, \bar{T} = 2.4V$ (figure B) $S3 = 1, R5 = 1k, C4 = 30pF$		24	35	ns
t_{PZHA} Propagation Delay from TRI-STATE to a Logical "1" from \bar{R} to A Port	$B0 \text{ to } B7 = 2.4V, \bar{T} = 2.4V$ (figure B) $S3 = 0, R5 = 5k, C4 = 30pF$		21	30	ns
B Port Data/Mode Specifications					
t_{PDHLB} Propagation Delay to a Logical "0" from A Port to B Port	$\bar{T} = 0.4V, \bar{R} = 2.4V$ (figure A) $R1 = 100\Omega, R2 = 1k, C1 = 300pF$ $R1 = 667\Omega, R2 = 5k, C1 = 45pF$		18	23	ns
			11	18	ns
t_{PDLHB} Propagation Delay to a Logical "1" from A Port to B Port	$\bar{T} = 0.4V, \bar{R} = 2.4V$ (figure A) $R1 = 100\Omega, R2 = 1k, C1 = 300pF$ $R1 = 667\Omega, R2 = 5k, C1 = 45pF$		16	23	ns
			11	18	ns
t_{PLZB} Propagation Delay from a Logical "0" to TRI-STATE from \bar{T} to B Port	$A0 \text{ to } A7 = 0.4V, \bar{R} = 2.4V$ (figure B) $S3 = 1, R5 = 1k, C4 = 15pF$		13	18	ns
t_{PHZB} Propagation Delay from a Logical "1" to TRI-STATE from \bar{T} to B Port	$A0 \text{ to } A7 = 2.4V, \bar{R} = 2.4V$ (figure B) $S3 = 0, R5 = 1k, C4 = 15pF$		8	15	ns
t_{PZLB} Propagation Delay from TRI-STATE to a Logical "0" from \bar{T} to B Port	$A0 \text{ to } A7 = 0.4V, \bar{R} = 2.4V$ (figure B) $S3 = 1, R5 = 100\Omega, C4 = 300pF$ $S3 = 1, R5 = 667\Omega, C4 = 45pF$		25	35	ns
			17	25	ns
t_{PZHB} Propagation Delay from TRI-STATE to a Logical "1" from \bar{T} to B Port	$A0 \text{ to } A7 = 2.4V, \bar{R} = 2.4V$ (figure B) $S3 = 0, R5 = 1k, C4 = 300pF$ $S3 = 0, R5 = 5k, C4 = 45pF$		24	35	ns
			17	25	ns

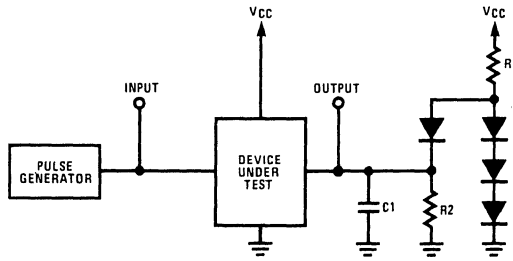
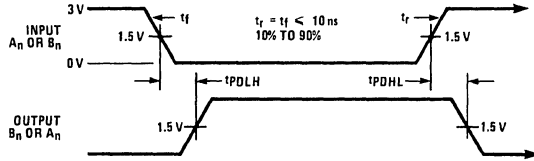
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the supply and temperature range listed in the table of Recommended Operating Conditions. All typical values given are for $V_{CC} = 5V$ and $T_A = 25^\circ C$.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

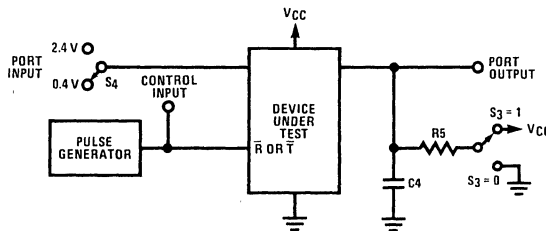
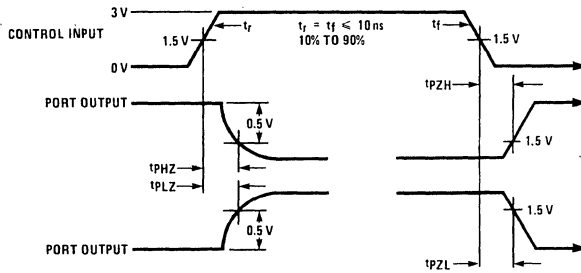
Note 4: Only one output at a time should be shorted.

Switching Time Waveforms and AC Test Circuits



NOTE: C1 INCLUDES TEST FIXTURE CAPACITANCE.

FIGURE A. Propagation Delay from A port to B port or from B port to A port



NOTE: C4 INCLUDES TEST FIXTURE CAPACITANCE. PORT INPUT IS IN A FIXED LOGICAL CONDITION. SEE AC TABLE.

Figure B. Propagation Delay to/from TRI-STATE from \bar{R} to A Port and \bar{T} to B Port

DS26S10, DS26S11 Quad Bus Transceivers

General Description

The DS26S10 and DS26S11 are quad Bus Transceivers consisting of 4 high speed bus drivers with open-collector outputs capable of sinking 100 mA at 0.8V and 4 high speed bus receivers. Each driver output is connected internally to the high speed bus receiver in addition to being connected to the package pin. The receiver has a Schottky TTL output capable of driving 10 Schottky TTL unit loads.

An active low enable gate controls the 4 drivers so that outputs of different device drivers can be connected together for party-line operation.

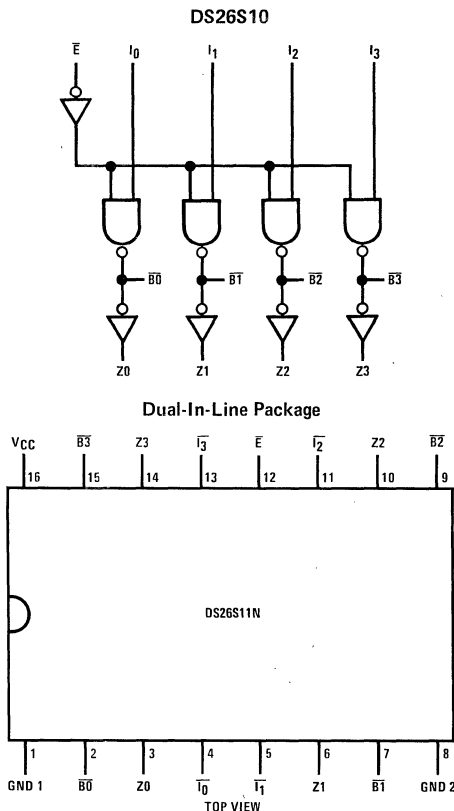
The bus output high-drive capability in the low state allows party-line operation with a line impedance as low as 100Ω. The line can be terminated at both ends, and still give considerable noise margin at the receiver. The receiver typical switching point is 2V.

The DS26S10 and DS26S11 feature advanced Schottky processing to minimize propagation delay. The device package also has 2 ground pins to improve ground current handling and allow close decoupling between VCC and ground at the package. Both GND 1 and GND 2 should be tied to the ground bus external to the device package.

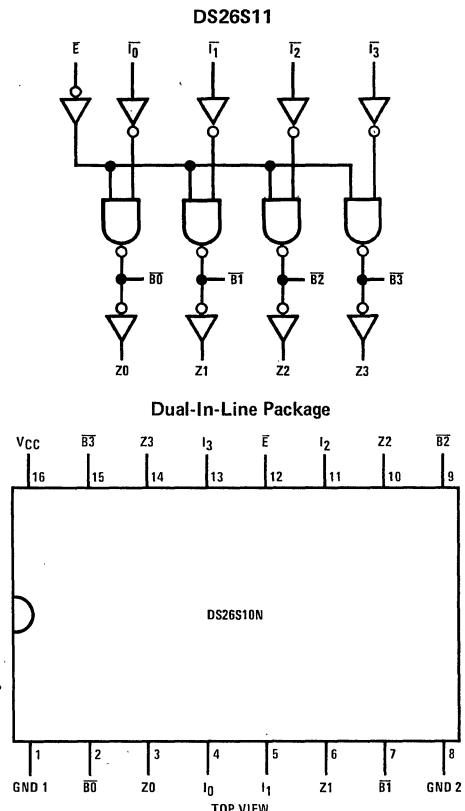
Features

- Input to bus is inverting on DS26S10
- Input to bus is non-inverting on DS26S11
- Quad high speed open-collector bus transceivers
- Driver outputs can sink 100 mA at 0.8V maximum
- Advanced Schottky processing
- PNP inputs to reduce input loading

Logic and Connection Diagrams



Order Number DS26S10J, DS26S10MJ
or DS26S10N
See NS Package J16A or N16A



Order Number DS26S11J, DS26S11MJ
or DS26S11N
See NS Package J16A or N16A

Absolute Maximum Ratings

Storage Temperature	-65°C to +150°C
Temperature (Ambient) Under Bias	-55°C to +125°C
Supply Voltage to Ground Potential	-0.5V to +7V
DC Voltage Applied to Outputs for High Output State	-0.5V to +V _{CC} Max
DC Input Voltage	-0.5V to +5.5V
Output Current, Into Bus	200 mA
Output Current, Into Outputs (Except Bus)	30 mA
DC Input Current	-30 mA to +5 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS26S10XC, DS26S11XC	4.75	5.25	V
DS26S10XM, DS26S11XM	4.5	5.5	V
Temperature (T _A)			
DS26S10XC, DS26S11XC	0	+70	°C
DS26S10XM, DS26S11XM	-55	+125	°C

Electrical Characteristics (Unless otherwise noted)

PARAMETER	CONDITIONS (Note 1)		MIN	TYP (Note 2)	MAX	UNITS
V _{OH} Output High Voltage (Receiver Outputs)	V _{CC} = Min, I _{OH} = -1 mA, V _{IN} = V _{IL} or V _{IH}	Military	2.5	3.4		V
		Commercial	2.7	3.4		V
V _{OL} Output Low Voltage (Receiver Outputs)	V _{CC} = Min, I _{OL} = 20 mA, V _{IN} = V _{IL} or V _{IH}				0.5	V
V _{IH} Input High Level (Except Bus)	Guaranteed Input Logical High for All Inputs		2.0			V
V _{IL} Input Low Level (Except Bus)	Guaranteed Input Logical Low for All Inputs				0.8	V
V _I Input Clamp Voltage (Except Bus)	V _{CC} = Min, I _{IIN} = -18 mA				-1.2	V
I _{IL} Input Low Current (Except Bus)	V _{CC} = Max, V _{IN} = 0.4V	Enable			-0.36	mA
		Data			-0.54	mA
I _{IH} Input High Current (Except Bus)	V _{CC} = Max, V _{IN} = 2.7V	Enable			20	μA
		Data			30	μA
I _I Input High Current (Except Bus)	V _{CC} = Max, V _{IN} = 5.5V				100	μA
I _{SC} Output Short-Circuit Current (Except Bus)	V _{CC} = Max, (Note 3)	Military	-20		-55	mA
		Commercial	-18		-60	mA
I _{CCL} Power Supply Current (All Bus Outputs Low)	V _{CC} = Max, Enable = Gnd	DS26S10		45	70	mA
		DS26S11			80	mA

Bus Input/Output Characteristics

PARAMETER	CONDITIONS (Note 1)		MIN	TYP (Note 2)	MAX	UNITS
V _{OL} Output Low Voltage	V _{CC} = Min	Military	I _{OL} = 40 mA	0.33	0.5	V
			I _{OL} = 70 mA	0.42	0.7	
			I _{OL} = 100 mA	0.51	0.8	
		Commercial	I _{OL} = 40 mA	0.33	0.5	
			I _{OL} = 70 mA	0.42	0.7	
			I _{OL} = 100 mA	0.51	0.8	
I _O Bus Leakage Current	V _{CC} = Max		V _O = 0.8V		-50	μA
		Military	V _O = 4.5V		200	
		Commercial	V _O = 4.5V		100	
I _{OFF} Bus Leakage Current (Power OFF)	V _O = 4.5V				100	μA
V _{TH} Receiver Input High Threshold	Bus Enable = 2.4V, V _{CC} = Max	Military	2.4	2.0		V
		Commercial	2.25	2.0		V
V _{TL} Receiver Input Low Threshold	Bus Enable = 2.4V, V _{CC} = Min	Military		2.0	1.6	V
		Commercial		2.0	1.75	V

Note 1: For conditions shown as min or max, use the appropriate value specified under Electrical Characteristics for the applicable device type.

Note 2: Typical limits are at V_{CC} = 5V, 25°C ambient and maximum loading.

Note 3: Not more than one output should be shorted at a time. Duration of the short circuit test should not exceed one second.

Switching Characteristics (T_A = 25°C, V_{CC} = 5V)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
t _{PLH}	Data Input to Bus	R _B = 50Ω, C _B = 50 pF (Note 1)	DS26S10	10	15	ns
t _{PHL}	Data Input to Bus			10	15	ns
t _{PLH}	Data Input to Bus		DS26S11	12	19	ns
t _{PHL}	Data Input to Bus			12	19	ns
t _{PLH}	Enable Input to Bus		DS26S10	14	18	ns
t _{PHL}	Enable Input to Bus			13	18	ns
t _{PLH}	Enable Input to Bus		DS26S11	15	20	ns
t _{PHL}	Enable Input to Bus			14	20	ns
t _{PLH}	Bus to Receiver Out	R _B = 50Ω, R _L = 280Ω, C _B = 50 pF (Note 1), C _L = 15 pF		10	15	ns
t _{PHL}	Bus to Receiver Out			10	15	ns
t _r	Bus	R _B = 50Ω, C _B = 50 pF (Note 1)	4.0	10		ns
t _f	Bus		2.0	4.0		ns

Note 1: Includes probe and jig capacitance

Truth Tables

DS26S10

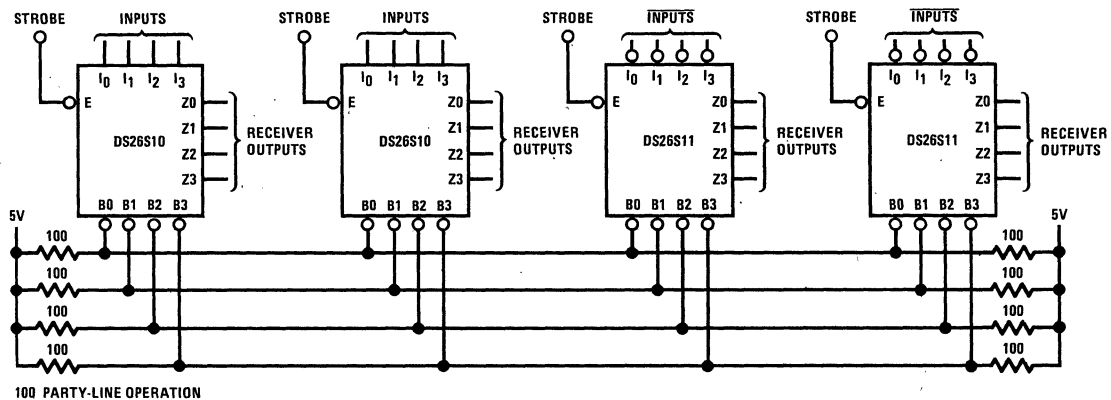
INPUTS		OUTPUTS	
\bar{E}	I	\bar{B}	Z
L	L	H	L
L	H	L	H
H	X	Y	\bar{Y}

DS26S11

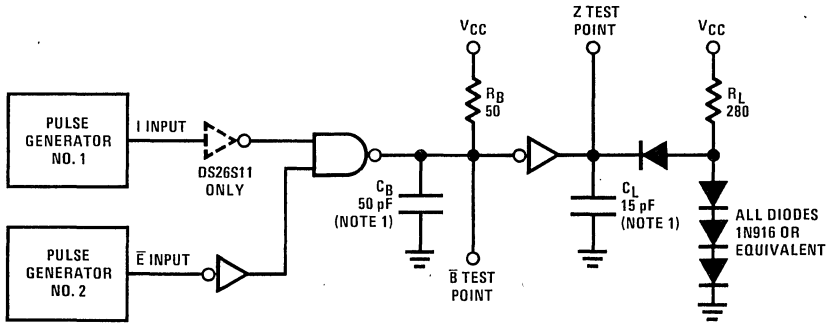
INPUTS		OUTPUTS	
\bar{E}	\bar{I}	\bar{B}	Z
L	L	L	H
L	H	H	L
H	X	Y	\bar{Y}

H = High voltage level
 L = Low voltage level
 X = Don't care
 Y = Voltage level of bus (assumes control by another bus transceiver)

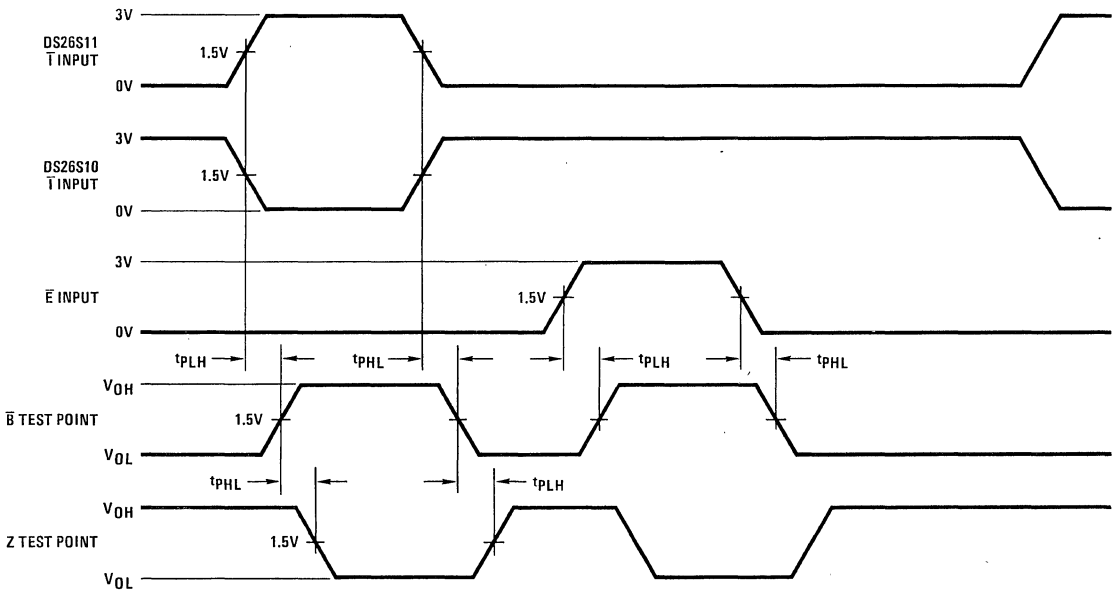
Typical Application



AC Test Circuit and Switching Time Waveforms

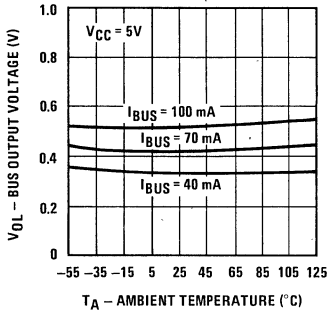


Note 1: Includes probe and jig capacitance.

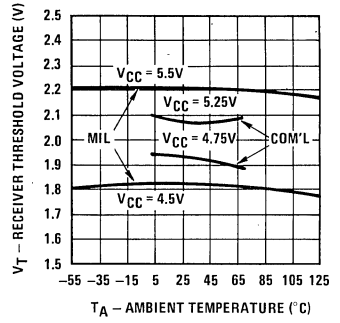


Typical Performance Characteristics

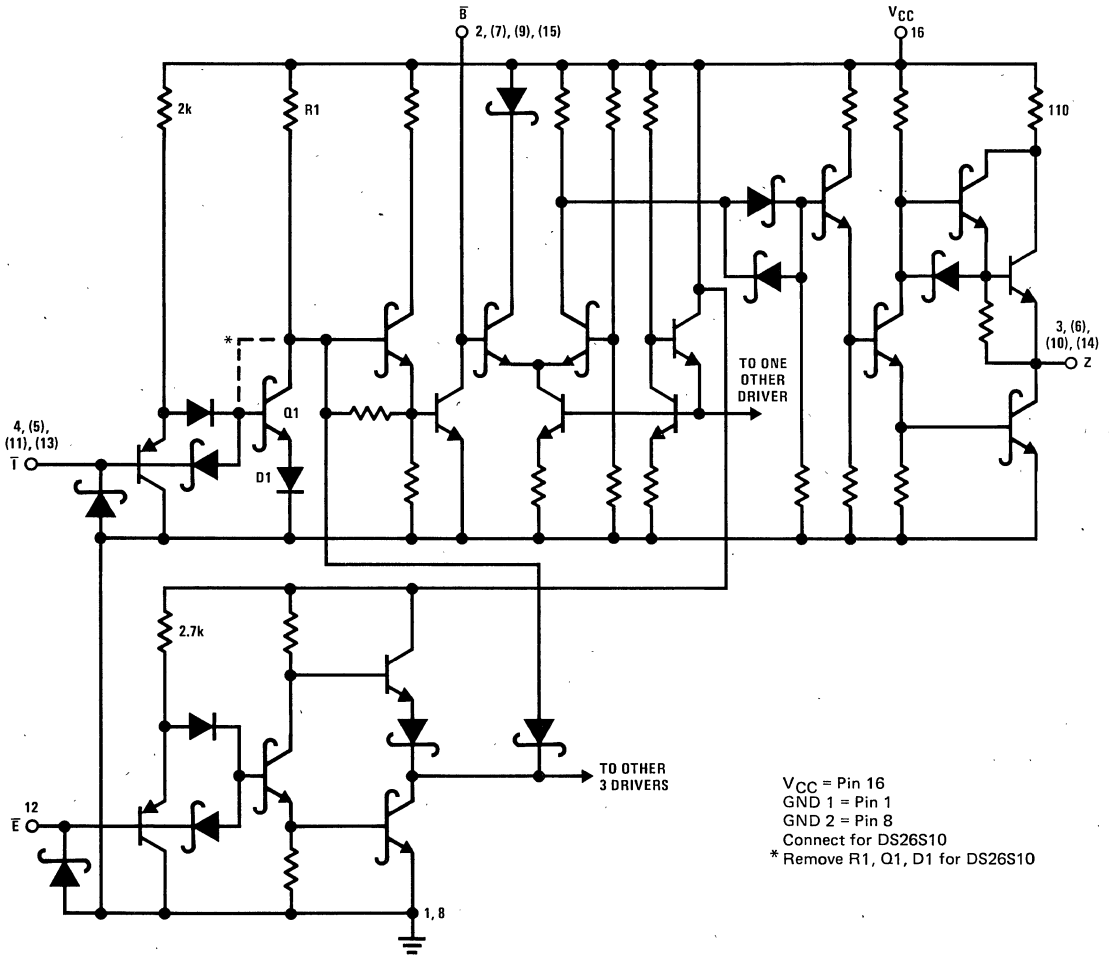
Typical Bus Output Low Voltage vs Ambient Temperature



Receiver Threshold Variation vs Ambient Temperature



Schematic Diagram



DS3662 Quad High Speed Trapezoidal™ Bus Transceiver

General Description

The DS3662 is a quad high speed Schottky bus transceiver intended for use with terminated 120Ω impedance lines. It is specifically designed to reduce noise in unbalanced transmission systems. The open collector drivers generate precise trapezoidal waveforms with rise and fall times of 15 ns (typical), which are relatively independent of capacitive loading conditions on the outputs. This reduces noise coupling to the adjacent lines without any appreciable impact on the maximum data rate obtainable with high speed bus transceivers. In addition, the receivers use a low pass filter in conjunction with a high speed comparator, to further enhance the noise immunity. Tightly controlled threshold levels on the receiver provide equal rejection to both negative and positive going noise pulses on the bus.

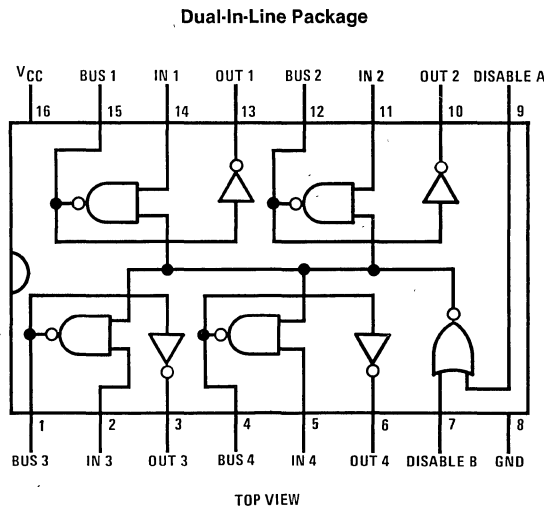
The external termination is intended to be a 180Ω resistor from the bus to 5V logic supply, together with a 390Ω resistor from the bus to ground. The bus can be terminated at one or both ends. A two input NOR gate is provided to disable all drivers in a package simultaneously.

Features

- Pin to pin functional replacement for DS8641
- Guaranteed AC specifications on noise immunity and propagation delay over the specified temperature and supply voltage range
- Temperature insensitive receiver thresholds track bus logic level
- Trapezoidal bus waveforms reduce noise coupling to adjacent lines
- Precision receiver thresholds provide maximum noise immunity and symmetrical response to positive and negative going pulses
- Open collector driver output allows wire-OR connection
- High speed Schottky technology
- 15 μA typical bus termination current with normal V_{CC} or with V_{CC} = 0V
- Glitch free power up/down protection on the driver output
- TTL compatible driver and disable inputs, and receiver outputs

2

Block and Connection Diagram



Order Number DS3662J or DS3662N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input and Output Voltage	5.5V
Storage Temperature Range	-65°C to 150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	4.75	5.25	V
Temperature Range (T_A)	0	70	°C

* Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

Parameter		Conditions	Min	Typ	Max	Units
DRIVER AND DISABLE INPUTS						
V_{IH}	Logical "1" Input Voltage		2.0			V
V_{IL}	Logical "0" Input Voltage				0.8	V
I_I	Logical "1" Input Current	$V_{IN} = 5.5V$			1	mA
I_{IH}	Logical "1" Input Current	$V_{IN} = 2.4V$			40	μA
I_{IL}	Logical "0" Input Current	$V_{IN} = 0.4V$		-1	-1.6	mA
V_{CL}	Input Diode Clamp Voltage	$I_{CLAMP} = -12\text{ mA}$		-0.8	-1.5	V
DRIVER OUTPUT/RECEIVER INPUT						
V_{OLB}	Low Level Bus Voltage	$V_{DIS} = 0.8V, V_{IN} = 2V, I_{BUS} = 100\text{ mA}$		0.6	0.9	V
I_{IHB}	Maximum Bus Current	$V_{IN} = 0.8V, V_{BUS} = 4V, V_{CC} = 5.25V$		10	100	μA
I_{ILB}	Maximum Bus Current	$V_{IN} = 0.8V, V_{BUS} = 4V, V_{CC} = 0V$			100	μA
V_{IH}	High Level Receiver Threshold	$V_{IN} = 0.8V, I_{OL} = 16\text{ mA}$	1.90	1.70		V
V_{IL}	Low Level Receiver Threshold	$V_{IN} = 0.8V, I_{OH} = -400\text{ }\mu A$		1.70	1.50	V
RECEIVER OUTPUT						
V_{OH}	Logical "1" Output Voltage	$V_{IN} = 0.8V, V_{BUS} = 0.5V, I_{OH} = -400\text{ }\mu A$	2.4	3.2		V
V_{OL}	Logical "0" Output Voltage	$V_{IN} = 0.8V, V_{BUS} = 4V, I_{OL} = 16\text{ mA}$		0.35	0.5	V
I_{OS}	Output Short Circuit Current	$V_{DIS} = 0.8V, V_{IN} = 0.8V, V_{BUS} = 0.5V, V_{OS} = 0V, V_{CC} = 5.25V, \text{ (Note 4)}$	-40	-70	-100	mA
I_{CC}	Supply Current	$V_{DIS} = 0V, V_{IN} = 2V$		50	90	mA

Switching Characteristics (Notes 2 and 3)

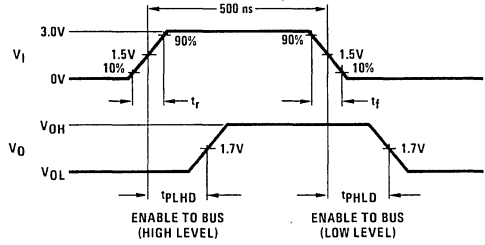
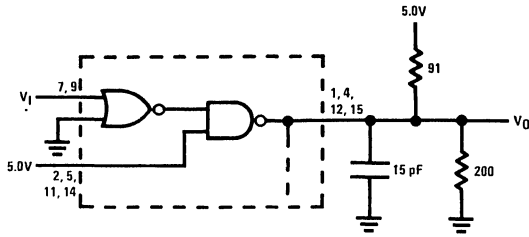
Parameter		Conditions	Min	Typ	Max	Units
PROPAGATION DELAYS						
t_{PLHD}	Disable to Bus "1"	Figure 1		25	35	ns
t_{PHLD}	Disable to Bus "0"			25	35	ns
t_{PLHB}	Driver Input to Bus "1"	Figure 2		20	30	ns
t_{PHLB}	Driver Input to Bus "0"			20	30	ns
t_{PLHR}	Bus to Logical "1" Receiver Output	Figure 3		25	40	ns
t_{PHLR}	Bus to Logical "0" Receiver Output			25	40	ns
NOISE IMMUNITY						
t_{rB}, t_{fB}	Rise and Fall Times (10%-90%) of the Driver Output	Figure 2	10	15	20	ns
t_{nR}	Receiver Noise Rejection Pulse Width	No Response at Receiver Output as per Figure 4		20	10	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" and "Recommended Operating Conditions" provide conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the supply and temperature range listed in the table of "Recommended Operating Conditions". All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5V$.

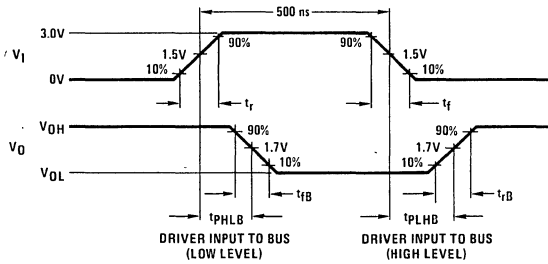
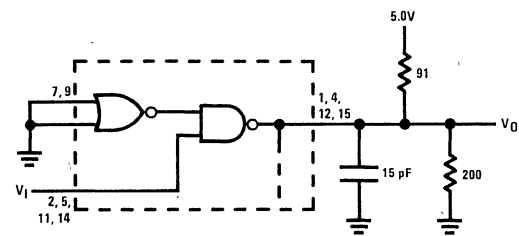
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.



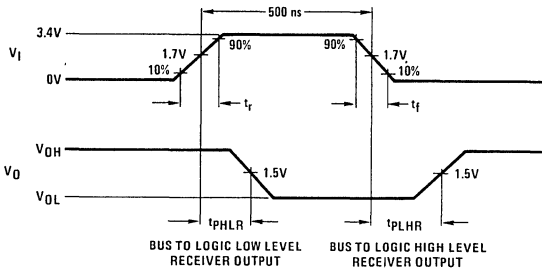
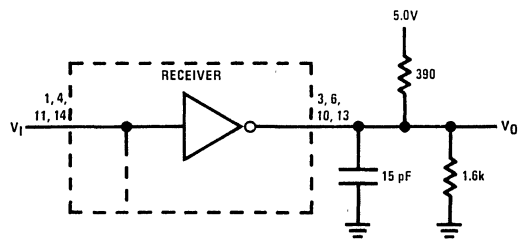
Note. $t_r = t_f = 2.5$ ns. Pulse width = 500 ns measured between 1.5V levels. $f = 1$ MHz.

FIGURE 1. Disable Delays



Note. $t_r = t_f = 2.5$ ns. Pulse width = 500 ns measured between 1.5V levels. $f = 1$ MHz.

FIGURE 2. Driver Propagation Delays



Note. $t_r = t_f = 15$ ns. Pulse width = 500 ns measured between 1.7V levels. $f = 1$ MHz.

FIGURE 3. Receiver Propagation Delays

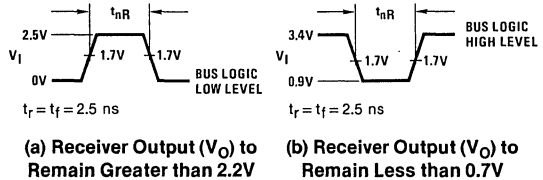
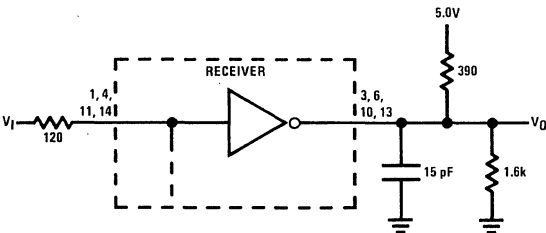
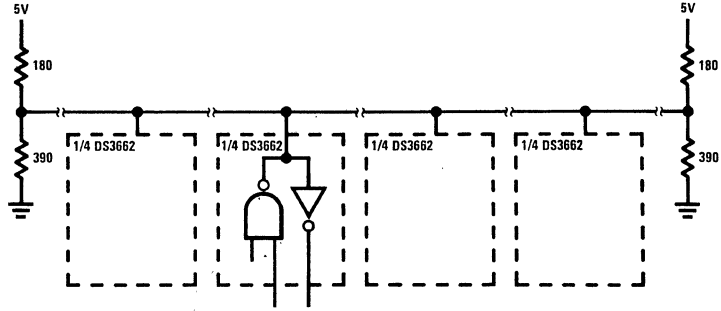


FIGURE 4. Receiver Noise Immunity: "No Response at Output" Input Waveforms

Typical Application

120Ω Unified Data Bus





I. Introduction

A single ended Bus is an unbalanced Data Transmission medium, which is timeshared by several system elements. Like any unbalanced system, it is highly susceptible to common-mode noise, such as ground noise and crosstalk. In general, the latter determines the maximum physical length of the Bus that can be incorporated with acceptable reliability. Crosstalk is a major problem in high speed computer Buses which employ Schottky Transceivers for increased data rate capability. It is therefore highly desirable to minimize crosstalk noise in Bus circuits to allow for longer Buses and to provide higher system reliability.

This article describes the operation of the DS3662 Quad High Speed Trapezoidal Bus Transceiver, which has been specially designed to minimize crosstalk problems. The Driver generates precise Trapezoidal waveforms that reduce noise coupling to adjacent Bus channels. The Receiver uses a low pass filter, whose time constant is matched to the Driver slew rate to provide maximum noise rejection with acceptable signal delay characteristics. Precision high speed circuitry optimizes noise immunity without sacrificing the high data rate capability of Schottky Transceivers.

II. The Problem

Conventional Bus Drivers are designed to provide high output currents for charging and discharging relatively large Bus capacitances quickly. These high speed transitions are characterized by peak slew rates of up to 5 volts/ns around the mid-region of the transition. This can cause considerable noise coupling to adjacent lines, commonly referred to as crosstalk. Crosstalk also

includes noise induced by sources external to the Bus. Additional noise may be generated due to reflections at imperfect terminations.

Bus Receivers are designed to respond to high speed transitions and to provide low propagation delays. Unfortunately, their fast response results in high noise sensitivity. The combined effect of the noise on the Bus and the sensitivity of the Receiver to the noise severely limits the Bus performance.

III. The Solution

The above situation can be considerably improved by employing noise reduction techniques in both the Driver and the Receiver circuits. Slew rate control can be used in the Driver to reduce crosstalk, and Receiver noise sensitivity can be reduced by using a low pass filter at its input. These techniques are commonly used in line transmission circuits where the associated data rates in general are considerably lower. However, these techniques do present some difficulties in high speed Bus circuits. Increased rise and fall times, resulting from slew rate control, can affect data rates unless care is taken to limit the maximum rise and fall times to minimum pulse width requirements. With any appreciable slew rate control, the rise and fall times of the resulting Driver output waveform will be comparable to the pulse widths at maximum data rates. This condition dictates high fidelity of the transmitted waveform and precise Receiver thresholds at the middle of the Bus voltage swing in order to minimize pulse width distortion. *Figure 1* illustrates the different sources of pulse width distortion due to the trapezoidal nature of the signal.

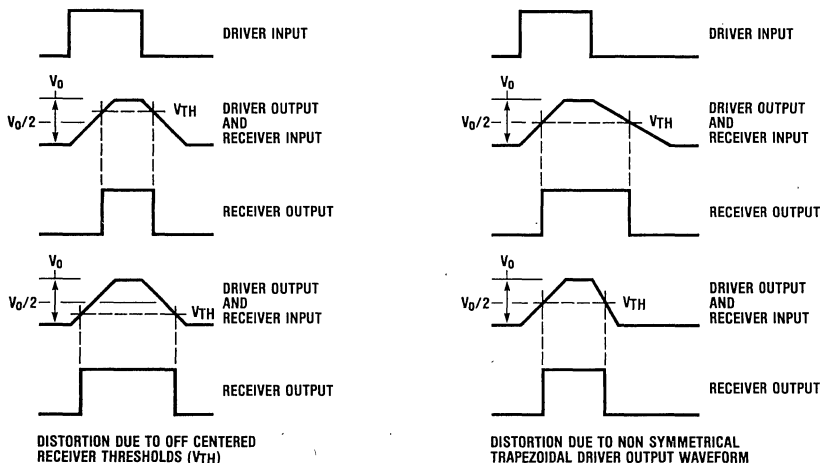


Figure 1. Pulse Width Distortion

The low pass filter in the Receiver should provide optimum noise rejection without introducing excessive delay in passing the signal waveform. In addition, the Receiver should have a symmetrical response to positive and negative going transitions in order to maintain a low level of pulse width distortion, as well as equal noise rejection to positive and negative going noise pulses. The response of an ideal low pass filter to signal and noise pulses is shown in *Figure 2*.

The DS3662 overcomes these and other problems by using high speed linear circuitry with on-chip capacitors for controlling slew rate and low pass filtering. The Driver is of open collector type intended for use with terminated 120 ohm Buses. The external termination consists of a 180 ohm resistor from the Bus to +5 volts logic supply with a 390 ohm resistor from the Bus to ground. Such a termination results in a Bus logic high level of 3.4 volts with V_{CC} at 5 volts (see *Figure 2*). The Bus can be terminated at one or both ends as shown in *Figure 3*.

IV. The Driver

Using a Miller integrator circuit, the Driver generates a linearly rising and falling waveform with a constant slew rate of 0.2 volts/ns (typical) during the entire period of transition. This corresponds to typical rise and fall times of 15 ns. *Figure 4* compares the output waveform of a typical Schottky Driver and the DS3662 under different capacitive loads. It should be noted that even under heavy loading, the regular Drivers have peak slew rates that are considerably higher than the average. In contrast, the trapezoidal waveform provides considerably lower slew rate with slightly higher rise and fall times. Such an increase in rise and fall time has very little effect on data rates. In fact, the high fidelity of the transmitted waveform allows pulse widths as low as 20 ns to be transmitted on the Bus, as shown in *Figure 5*.

The block diagram of the Driver is shown in *Figures 6* and *7*. When a high to low transition is applied to the input, switch 'S' opens and node 'A' is pulled low by the current source 'I'. This switches the amplifier output to a high state. The slew rate of the output transition is limited by the charging current through the capacitor, a constant value equal to I/C volts/sec.

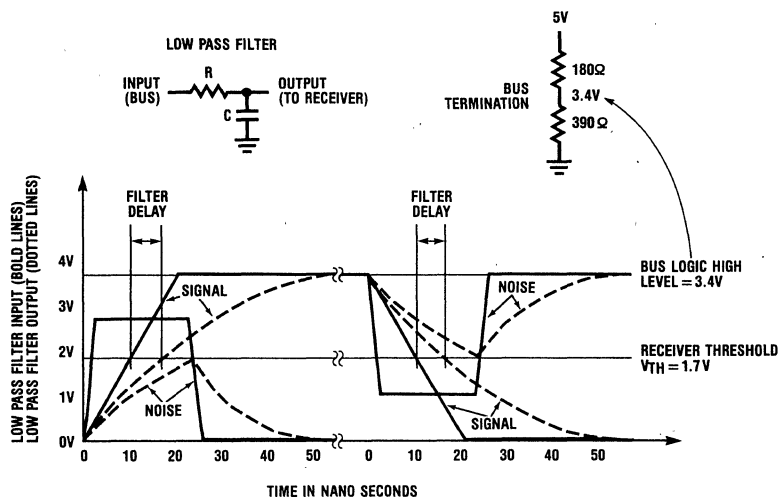


Figure 2. Ideal Receiver Low Pass Filter Response

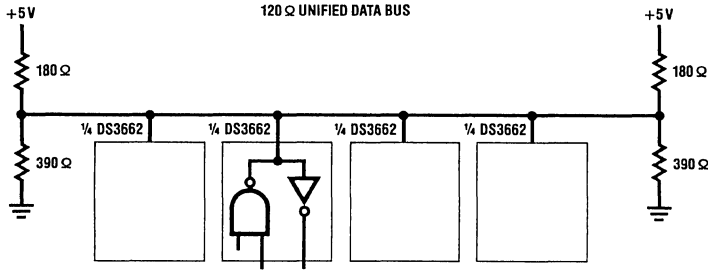
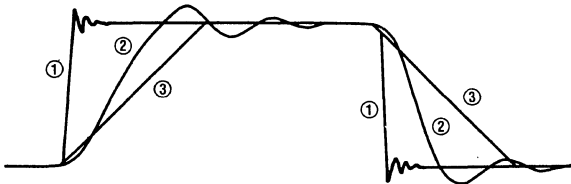


Figure 3. Bus Termination



- ①— TYPICAL HIGH SPEED DRIVER OUTPUT UNLOADED
 - ②— TYPICAL HIGH SPEED DRIVER OUTPUT LOADED
 - ③— TYPICAL OUTPUT OF CONTROLLED SLEW RATE DRIVER WHICH IS LOAD INDEPENDENT
- ① $t_r = t_f \approx 3$ ns
 ② $t_r = t_f \approx 10$ ns
 ③ $t_r = t_f \approx 15$ ns
- NOTE: THE WORD 'LOADING' HERE REFERS TO CAPACITIVE LOADING ONLY.

Figure 4. Waveform Comparison

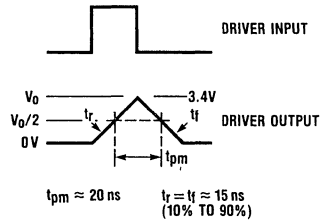


Figure 5. Minimum Pulse Width Driver Output

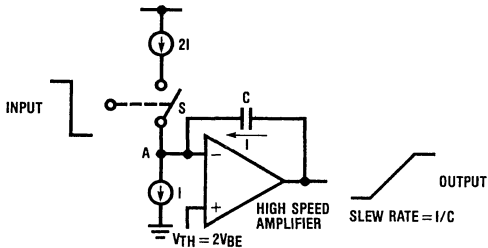


Figure 6. Driver

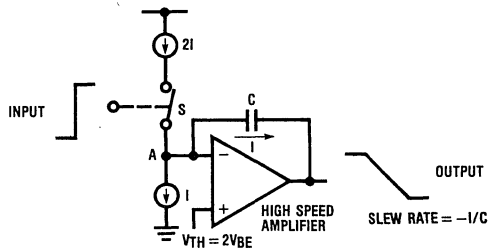


Figure 7. Driver

Likewise, when a low to high transition is applied to the input, switch 'S' closes and node 'A' is pulled up by the '2I' current source, switching the amplifier output to a low state. The capacitor now has an equal but opposite charging current which once again limits the slew rate to $-I/C$ volts/sec. The inherent tracking ability of I.C. current sources provide equal rise and fall times resulting in a symmetrical output waveform.

The on-chip capacitors are fabricated using back to back junction diodes. The use of junction capacitors reduces die area and the back to back connection allows operation with either polarity. The capacitor terminal, connected to the amplifier input, remains at $V_{th} \approx 1.6$ volts during the output transition. This voltage, being close to the middle of the output swing, reduces the effect of the capacitor voltage sensitivity on the output waveshape.

V. The Receiver

The Receiver consists of a low pass filter followed by a high speed comparator with a typical threshold of 1.7 volts (see Figure 8). This threshold value corresponds to the mid-point voltage of the 0 to 3.4 volt Bus swing. It is derived from a potential divider allowing the Bus logic levels to track with V_{CC} variations. If the low pass filter capacitor is voltage insensitive, this circuit will provide equal propagation delay for positive and negative going signal transitions on the Bus. In addition, it will also provide equal noise rejection to a positive and negative

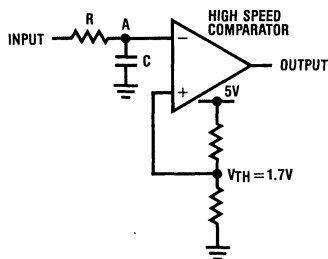


Figure 8. Receiver

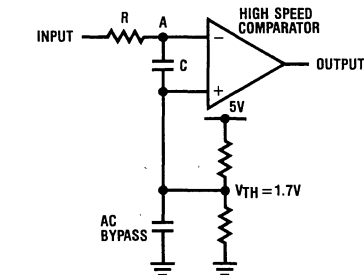
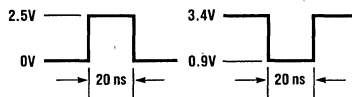


Figure 9. Receiver



REJECTS POSITIVE OR NEGATIVE GOING NOISE PULSES OF PULSE WIDTHS UP TO 20 ns TYPICAL.
DETECTS AND PROPAGATES TRAPEZOIDAL SIGNAL PULSES IN 20 ns TYPICAL.

Figure 10. Receiver Noise Immunity

going pulse (see Figure 2). However, the junction capacitors, being voltage sensitive, will exhibit non-symmetrical response in the above circuit. This problem is overcome in the DS3662 Receiver by using a back to back junction capacitor with the ground end biased at 1.7 volts (see Figure 9). Although the capacitor still varies with the voltage at node 'A', the variation is symmetrical about 1.7 volts (the middle of the Bus swing) and therefore will provide an identical response to transitions of either polarity.

VI. Transceiver Performance

The characteristics of the trapezoidal Transceiver are fully detailed in the device data sheet. Some of the more important specifications are discussed below. Both AC and DC specifications are guaranteed over a 0-70°C temperature range and a supply range of 4.75-5.25 volts.

The Driver typically has a propagation delay of 15ns with a maximum of 30ns. The Receiver propagation delays are specified at 25ns typical and 40ns maximum. The Driver output rise and fall times are guaranteed to be within 10 to 20ns with a typical of 15ns. The noise immunity of the Receiver is specified in terms of the width of a 2.5 volt pulse that is guaranteed to be rejected by the Receiver (see Figure 10). The Receiver typically rejects a 20ns pulse going positive from ground level or going negative from a 3.4 volt logic 1 level. Worst case rejection is specified at 10ns.

The AC response of the DS3662 Driver and Receiver are depicted in *Figures 11 and 12* respectively. *Figure 11* shows the typical Driver output waveform as compared to a standard high speed Transceiver output. Oscillograms in *Figure 12* demonstrate the ability of the Receiver to distinguish the trapezoidal signal from the noise. Here the Receiver rejects a noise pulse of 19ns width, while accepting a narrower signal pulse (= 16ns) of the same amplitude (The signal is triangular since the pulse width is smaller than the rise and fall time of the Trapezoidal Driver output).

The performance of the Transceiver under actual operating condition is demonstrated in *Figures 13* through *15*. Oscillograms in *Figure 13* clearly show the capability of the DS3662 in real life situations. Here it is compared with the DS8834 under identical conditions. The Transceivers drive a minicomputer Bus (flat ribbon cable) 100 feet long, terminated at the far end with taps at various lengths for connecting to the Receiver input. The cable is randomly folded to generate crosstalk between the various parts. In addition a noise pulse is induced on the signal line by driving an adjacent line with a pulse generator. This corresponds to the second dominant pulse in the Bus waveforms at approximately 600ns from the main signal pulse. As can be seen, the DS8834 with fast rise and fall times on the Driver output generates more crosstalk and its Receiver easily responds to this crosstalk and to the externally induced noise (even though it has hysteresis!), limiting the use-

ful Bus length to less than 10 feet. In contrast, the DS3662's Driver generates much less crosstalk and its Receiver is immune to the induced noise even when the noise amplitude exceeds the signal amplitude as seen in the oscillogram at 50 feet. When the same experiment was repeated with the DS8641, it responded to the noise even at 10 feet as shown in *Figure 14*.

Figure 15 shows the plots of maximum data rate versus line length for the three Transceivers discussed above under two different conditions. The graph in *Figure 15a* is obtained with no consideration to the pulse width distortion whereas the one in *Figure 15b* is obtained for a maximum allowable pulse width distortion of $\pm 10\%$. A square waveform is used so that the pulse width distortion criteria will apply to both positive and negative going pulses. These graphs clearly show that the DS3662 can be used at considerably higher data rates with lower distortion for longer distances than the other two Transceivers (*Figure 15b*) although the others have a slightly higher data rate capability at short distances with high timing distortion (*Figure 15a*).

VII. Conclusion

The DS3662, with its combination of a trapezoidal Driver and a noise rejecting Receiver utilizing on chip capacitors, represents a significant improvement in high speed Bus circuits and a solution to Bus noise problems commonly encountered in Mini and Microcomputer systems.

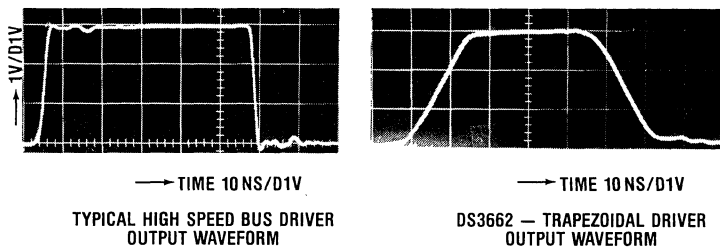


Figure 11.

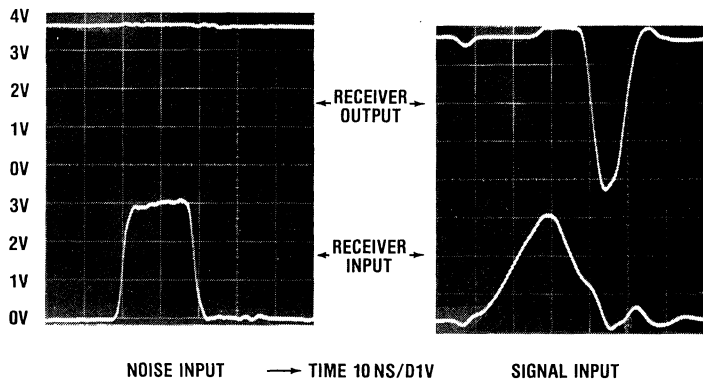
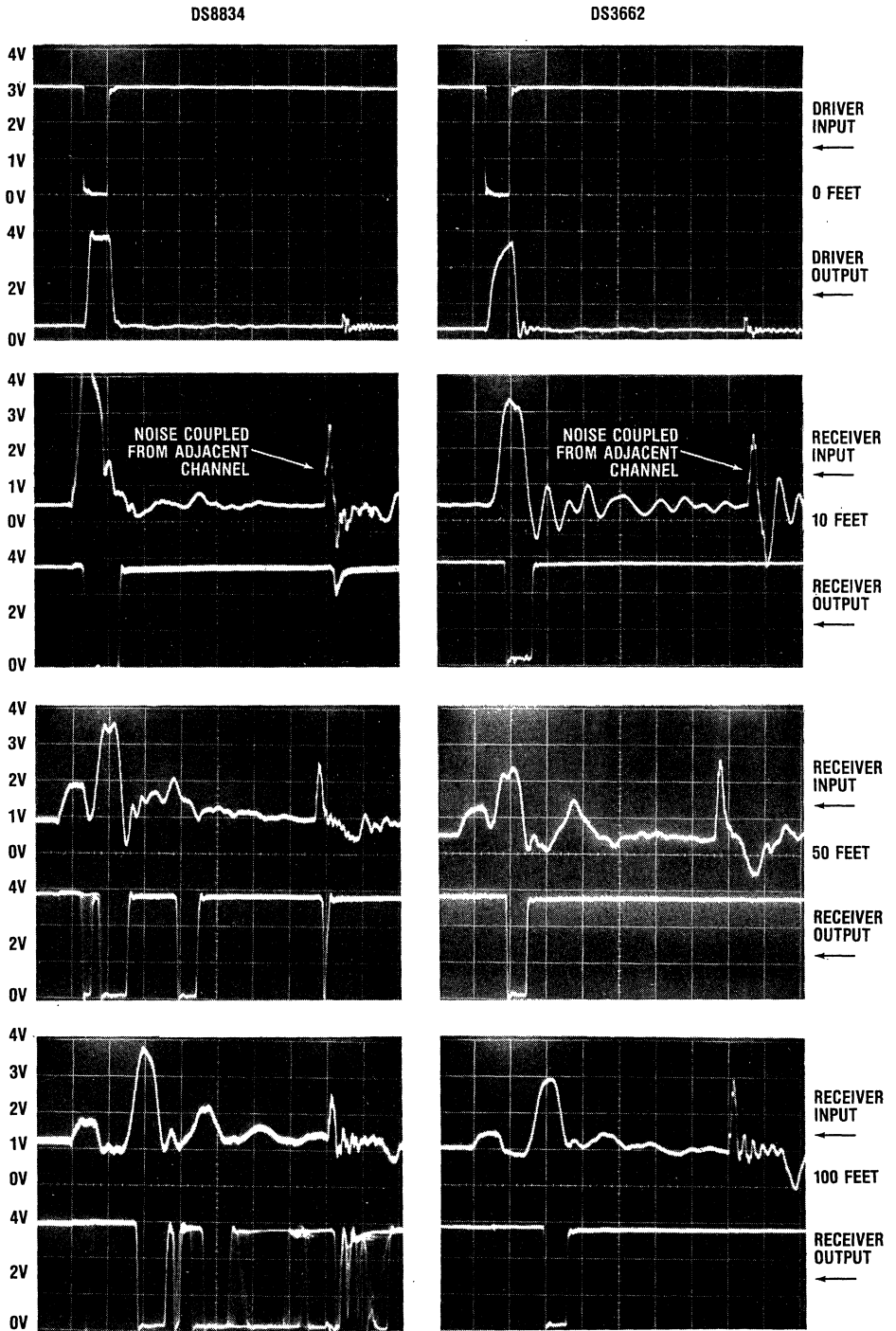


Figure 12. DS3662 Receiver Response



→ TIME 100 NS/DIV

Figure 13.

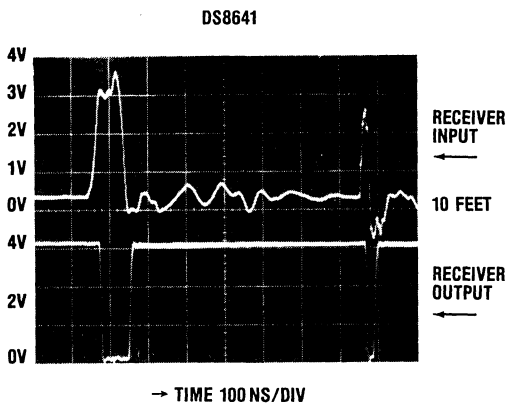


Figure 14.

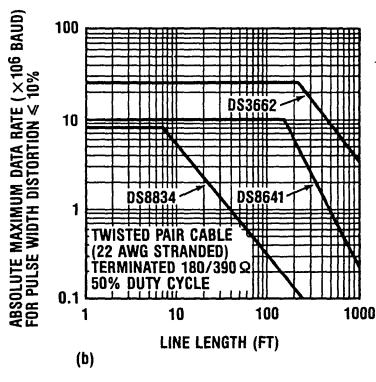
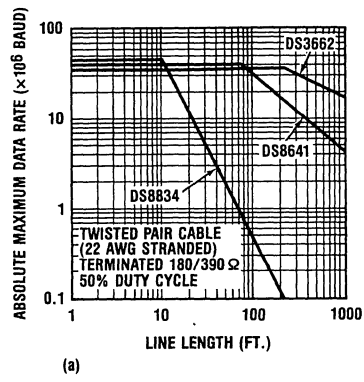


Figure 15. Data Rate vs. Line Length

Reducing Noise on Microcomputer Buses

National Semiconductor
Application Note 337
R. V. Balakrishnan
May 1983



Abstract: This paper focuses on the noise components that have a significant impact on the performance of a high speed microcomputer bus. An overview of their nature is followed by ways to minimize their contribution by suitable design of the PC board backplane, the termination network and the bus transceiver. The DS3662 trapezoidal bus transceiver, which is specifically designed to minimize such noise on high speed buses, is presented along with its performance data. And to conclude, some possible new transceiver designs for further improvement of the bus performance are explored.

INTRODUCTION

As the microcomputer bus bandwidth is extended to handle ever increasing clock rates, the noise susceptibility of a single-ended bus poses a serious threat to the overall system integrity. Thus, it is mandatory that the various noise contributions be taken into account in the design of the bus transceiver, the PC board backplane and the bus terminations to avoid intermittent or total failure of the system.

Although noise such as crosstalk and reflections are inevitable in any practical bus configuration, their impact on the system can be determined and minimized by careful design of all three components mentioned above. The combined contribution of the noise under worst-case conditions should be within the noise margin for reliable bus operation.

The design of the transceiver plays a significant role in minimizing crosstalk and reflection. The bus can be optimized for minimum noise at a given bandwidth by using a trapezoidal driver having suitable rise and fall times along with a matched low pass filtered receiver which provides a symmetrical noise margin. The DS3662 is one such transceiver, the first member in the family of trapezoidal bus transceivers available from National Semiconductor Corporation. This device represents a significant improvement in high speed bus circuit design and provides a solution to commonly encountered bus noise problems.

THE MICROCOMPUTER BUS

A typical microcomputer bus usually consists of a printed circuit board backplane with signal and ground traces on one side and a ground plane on the other. The length ranges from a few inches to several feet with as many as 32 closely spaced (0.6" typical) card edge connectors. Each signal line interacts with the ground plane to form a transmission line with characteristic impedance 'Z' in the range of 90Ω-120Ω typical. It is desirable to have as large a 'Z' as possible in order to reduce the drive requirement of the bus driver and to reduce the power dissipated at the terminations. But much larger values of 'Z' translate to significantly larger physical dimensions and therefore are not very practical.

The bus appears like a transmission line to any signal having a transition time 't_r' less than the round trip delay '2T_L' of the bus. The bus delay 'T_L' is given by:

$$T_L = L \sqrt{L_1 C_1} \quad (1)$$

where L = length of the bus
L₁ = distributed inductance per unit length
C₁ = distributed capacitance per unit length

For a typical unloaded 100Ω microstrip line, C₁ = 20 pF/ft and L₁ = 0.2 μH/ft. Therefore, T_L = 2.0 ns/ft. This corresponds to approximately half the speed of light. However, the capacitive loading at each connector on the backplane increases the delay time significantly. The loaded delay time 'T_{LL}' is given by:

$$T_{LL} = T_L \sqrt{1 + (C_L/C_1)} \quad (2)$$

where C_L = distributed load capacitance/unit length

Given a 10 pF loading at each connector (connector + transceiver capacitance) and a 0.6" spacing between connectors, C_L = 200 pF/ft and T_{LL} = 6.6 ns/ft. So even a 6" long bus has a 2T_{LL} = 6.6 ns, which is higher than the transition time (t_r) of many high speed bus drivers. When in doubt, it is always better to use the transmission line approach than the lumped circuit approach as the latter is an approximation of the former. Also, the transmission line analysis gives more pessimistic (worst-case) values of crosstalk and reflection and is, hence, safer.

CROSSTALK REDUCTION

The crosstalk is due to the distributed capacitive coupling C_C and the distributed inductive coupling L_C between two lines. When crosstalk is measured on an undriven sense line next to a driven line (both terminated at their characteristic impedances), the near end crosstalk and the far end crosstalk have quite distinct features, as shown in Figure 1. Their respective peak amplitudes are:

$$V_{NE} = K_{NE}(2T_L)(V_1/t_r) \quad \text{for } t_r > 2T_L \quad (3)$$

$$V_{NE} = K_{NE}(V_1) \quad \text{for } t_r < 2T_L \quad (4)$$

$$V_{FE} = K_{FE}(L)(V_1/t_r) \quad (5)$$

where V₁ = signal swing on the drive line.

The coupling constants are given by the expressions:

$$K_{NE} = \frac{L(C_C Z + L_C/Z)}{4T_L} \quad (6)$$

$$K_{FE} = \frac{C_C Z - L_C/Z}{2} \quad \text{ns/ft} \quad (7)$$

The near end component reduces to zero at the far end and vice versa. At any point in between, the crosstalk is a fractional sum of near and far end crosstalk waveforms shown.

It should be noted from expressions 6 and 7 that the far end crosstalk can have either polarity whereas the near end crosstalk always has the same polarity as the signal causing it. In microstrip backplanes the far end crosstalk pulse is usually the opposite polarity of the original signal.

Although the real world bus is far from the ideal situation depicted in *Figure 1*, several useful observations that apply to a general case can be made:

1. The crosstalk always scales with the signal amplitude.
2. Absolute crosstalk amplitude is proportional to slew rate V_I/t_r , not just $1/t_r$.
3. Far end crosstalk width is always t_r .
4. For $t_r < 2T_L$, the near end crosstalk amplitude V_{NE} expressed as a fraction of signal amplitude V_I is a function of physical layout only.
5. The higher the value of ' t_r ' the lower the percentage of crosstalk (relative to signal amplitude).

The corresponding design implications are:

1. The noise margin expressed as a percentage of the signal swing is what's important, not the absolute noise margin. Therefore, to improve noise immunity, the percentage noise margin has to be maximized. This is achieved by reducing the receiver threshold uncertainty region and by centering the threshold between the high and low levels.

2. Smaller signal amplitude with the same transition time reduces bus drive requirements without reducing noise immunity.
3. Far end crosstalk is eliminated if the receiver is designed to reject pulses having pulse widths less than or equal to t_r .
4. When $t_r < 2T_L$, the near end crosstalk immunity for a given percentage noise margin has to be built into the backplane PC layout. Since $(V_{NE}/V_I) = K_{NE}$ for this case, K_{NE} should be kept lower than the available worst-case noise margin. K_{NE} may be reduced by either increasing the spacing between lines or by introducing a ground line in between. The ground line, in addition to increasing the spacing between the signal lines, forces the electric field lines to converge on it, significantly reducing crosstalk.
5. For minimum crosstalk the rise and fall times of the signal waveform should be as large as possible consistent with the minimum pulse width requirements of the bus. A driver that automatically limits the slew rate of the transition can go a long way in reducing crosstalk.

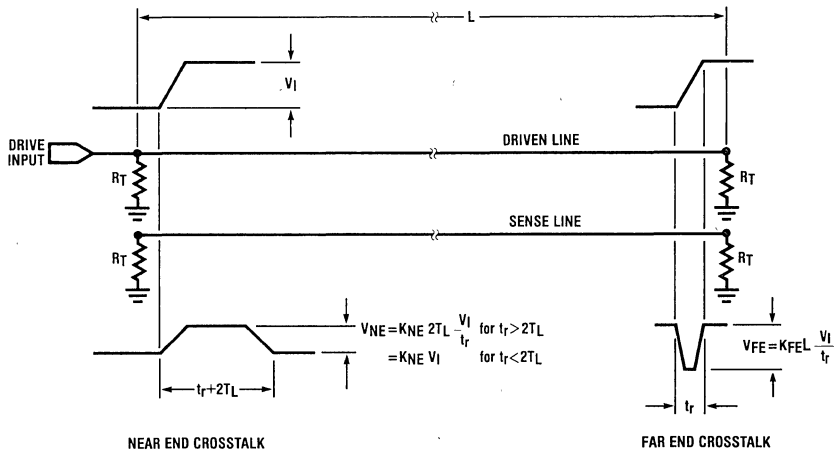


FIGURE 1. Crosstalk Under Ideal Conditions

CROSSTALK MEASUREMENT

When multiple lines on either side of the sense lines switch simultaneously the crosstalk is considerably larger, typically 3.5 times the single line switching case for microstrip backplanes. Also, the location of the drivers on the driven lines and the receiver on the sense line for worst-case crosstalk differs for the near end and far end cases as shown in *Figures 2 and 3* for a uniformly loaded bus. But if the far end crosstalk is not of the opposite polarity, then the combined effect of far end and near end crosstalk could have a larger amplitude and pulse width at a point near the middle of the sense line in *Figure 2*. So in a general case, or in the case of a non-uniformly loaded bus, it is advisable to check the sense line at several locations along the length of the bus to determine the worst-case crosstalk. The measurement should be made for both the positive and the negative transition of the drive signal.

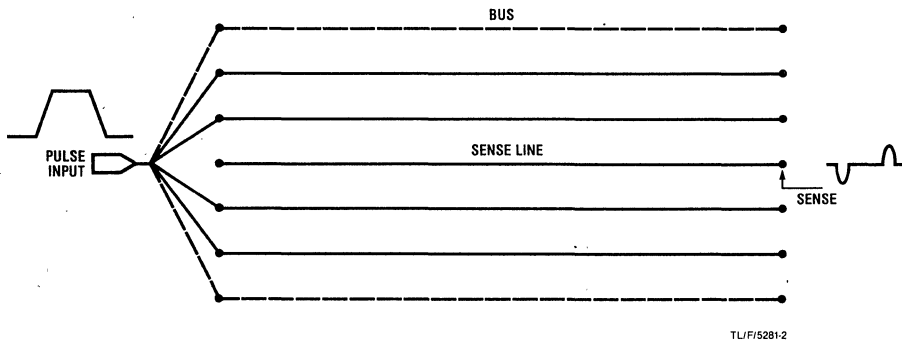
THE TERMINATION

A properly terminated transmission line has no reflections. But a practical microcomputer bus is neither a perfect transmission line nor is it properly terminated under all conditions. The capacitive loading at discrete locations, such as a used card slot, act as sources of reflection. However, in the limiting case when the bus is uniformly populated with a large number of modules, the bus behaves like a lower impedance transmission line. The loaded impedance 'Z_L' of the bus is given by the expression:

$$Z_L = \frac{Z}{\sqrt{1 + C_L/C_1}} \tag{8}$$

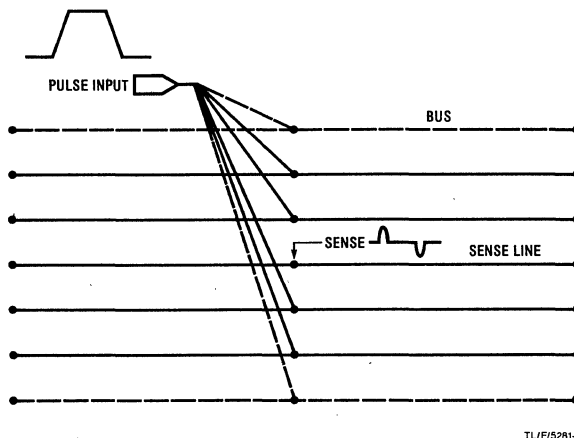
where Z = unloaded line impedance

Unfortunately, uniform loading of the bus is not guaranteed at all times and even if it were (by dummy loading of



Note: All lines terminated at both ends (not shown)

FIGURE 2. Worst-Case Far End Crosstalk Measurement



Note: All lines terminated at both ends (not shown)

FIGURE 3. Worst-Case Near End Crosstalk Measurement

the unused slots) Z_L is usually too low for proper termination of the bus. For example, a 10 pF per module loading of the 100 Ω microstrip bus at 0.6" spacing results in a $Z_L = 30\Omega$. One such termination at each end will require a 200 mA drive capacity on the bus driver for a nominal 3V swing. Such large drive currents and low value terminations increase the power dissipation of the system significantly in addition to causing other problems such as increased ground drop, inductive drops in traces due to large current being switched, etc. As a compromise the bus is usually terminated at an impedance higher than Z_L but less than or equal to Z . Consequently, there is always some amount of reflection present. For a perfect transmission line the reflection coefficient Γ is given by the well known expression:

$$\Gamma = \frac{Z - R_t}{Z + R_t} \quad (9)$$

where Z = impedance of the bus
 R_t = termination resistance

The net effect, in the general case of a nonuniformly loaded bus, is that it may take several round trip bus delays after a bus driver output transition, before the quiescent voltage level is established. However, this delay is avoided by using a bus driver that has sufficient drive to generate a large enough voltage step during the first transition to cross well beyond the receiver threshold region under the worst-case load conditions.

Figure 4 illustrates the driver output waveform under such a condition. Here the fully loaded bus (with $Z_L = 30\Omega$), of the previous example, is driven by the DS3662 bus transceiver at the mid point. The driver is actually driving two transmission lines of $Z_L = 30\Omega$ in either direction from the middle and hence the initial step is given by:

$$V_1 = \left(\frac{Z_L}{2} \right) 2I_S \quad (10)$$

where I_S = Standing current on the bus due to each termination

For the DS3662, the termination can be designed for $2I_S = 100$ mA and therefore:

$$V_1 = (30/2)100 = 1.5V$$

This value of the initial swing is large enough to cross the narrow threshold region of the receiver as shown and therefore no waiting period is required for the reflections to build up the output high level. On the negative transition the problem is less critical due to the much higher sink capability of the DS3662 during pull down.

Reflections can also be caused by resistive loading of the bus by the DC input current of the receiver. The resulting reflection coefficient (Γ) is given by the expression:

$$\Gamma = -1/2 \left(\frac{I_R}{I_S} \right) \quad (11)$$

where I_R = receiver input current

Having a receiver with a high input impedance not only makes this component of reflection insignificant but also reduces the DC load on the driver, allowing the use of lower value termination resistors. This is particularly true when a large number of modules are connected to the bus.

The design implications of the above discussion may be summarized as follows:

1. If the driver has adequate drive to produce the necessary voltage swing under the worst-case loading ($Z_L/2$), reflections do not restrict the bus performance. This translates to a 100 mA minimum drive requirement for a typical microstrip bus.
2. If the drive is insufficient, time should be allowed for the reflections to build up the voltage level before the data is sampled.
3. For signals such as clock, strobe, etc., wherein the edge is used for triggering events, it is mandatory that the driver meet the above drive requirements if delayed or multiple triggering is to be avoided.
4. An ideal TTL bus transceiver should have at least a 100 mA drive, a high input impedance receiver with a narrow threshold uncertainty region.

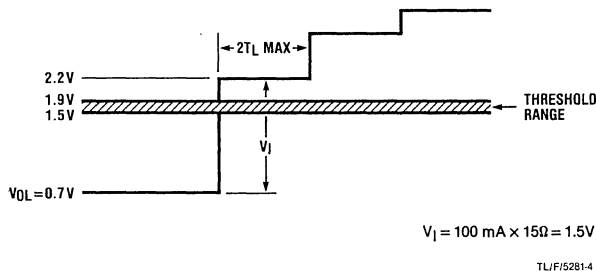


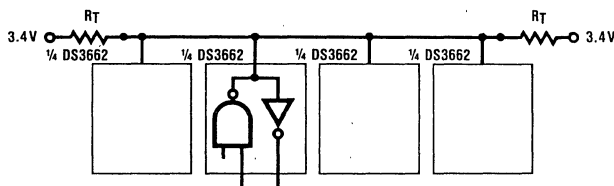
FIGURE 4. Worst-Case DS3662 Output Transition for $Z_L = 15\Omega$ and $R_T = 50\Omega$

THE DS3662 TRANSCEIVER

The DS3662 quad trapezoidal bus transceiver has been designed specifically to minimize the noise problems discussed previously. The driver generates precise trapezoidal waveforms that reduce crosstalk and the receiver uses a low pass filter to reject noise pulses having pulse widths up to the maximum driver output transition times. Precision output circuitry optimizes noise immunity without sacrificing the high data rate capability of Schottky transceivers.

Figure 5 shows the recommended configuration for microcomputer buses. The use of a 3.4V source with a single termination resistor at each end reduces the average power dissipation of the bus. However, a two resistor termination connected between the line and the power rails, having the same Thevenin's equivalent, can be substituted for lower cost.

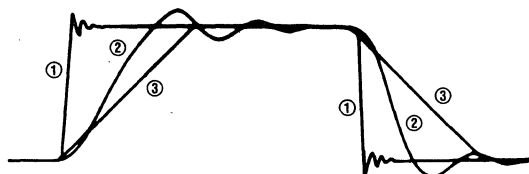
Using a Miller integrator circuit, the driver generates a linearly rising and falling waveform with a constant slew rate of $0.2 V/ns$ (Figure 7). This corresponds to a nominal transition time of 15 ns. Figure 6 compares the output waveform of a typical high speed driver to that of DS3662 under different load conditions. It should be noted that even under heavy loading, the regular drivers have peak slew rates that are much higher than the average. On the other hand, the trapezoidal waveform has a much lower slew rate with only a slight increase in the transition time. Such an increase in the transition time has little or no effect on the data rates. In fact, the high fidelity of the DS3662 driver output waveform allows pulse widths as low as 20 ns to be transmitted on the bus.



$R_T = 50\Omega$ to 90Ω

TL/F/5281-5

FIGURE 5. Recommended Bus Termination for Heavily Loaded Microstrip Backplanes



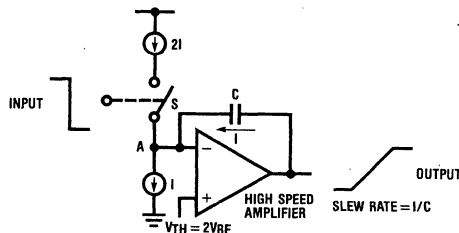
TL/F/5281-6

Note 1: Typical high speed driver output unloaded; $t_r = t_f \approx 3$ ns

Note 2: Typical high speed driver output loaded; $t_r = t_f \approx 10$ ns

Note 3: Typical output of controlled slew rate driver which is load independent; $t_r = t_f = 15$ ns

FIGURE 6. Waveform Comparison



TL/F/5281-7

FIGURE 7. DS3662 Driver

The receiver consists of a low pass filter followed by a high speed comparator, with a typical threshold of 1.7V (Figure 8). The noise immunity of the receiver is specified in terms of the width of a 2.5V pulse that is guaranteed to be rejected by the receiver (Figure 9). The receiver typically rejects a 20 ns pulse going positive from the ground level or going negative from the 3.4V logic 1 level. The receiver threshold lies within a specified 400 mV region over the supply and temperature range and is centered between the low and high levels of the bus for a symmetrical noise margin.

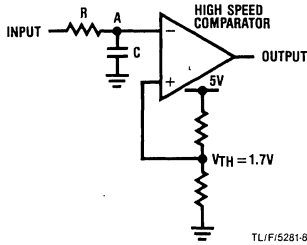
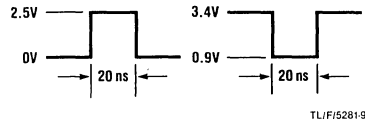


FIGURE 8. DS3662 Receiver

Other features of the device include a 100µA maximum DC bus loading specification under power ON or OFF condition and a glitch-free power up/down protection on the bus output.

Figure 10 shows the typical driver output waveform as compared to a standard high speed transceiver output. Oscillograms in Figure 11 demonstrate the ability of the receiver to distinguish the trapezoidal signal from noise. Here the receiver rejects a noise pulse of 19 ns width, while accepting a narrower signal pulse (16 ns) of the same peak amplitude (the signal is triangular because of the pulse width which is smaller than the transition time).



Rejects positive or negative going noise pulses of pulse widths up to 20 ns typical. Detects and propagates trapezoidal signal pulses in 20 ns typical.

FIGURE 9. Receiver Noise Immunity

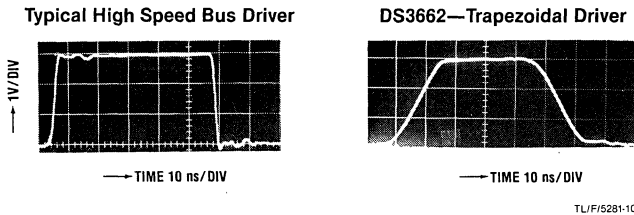


FIGURE 10. Output Waveforms

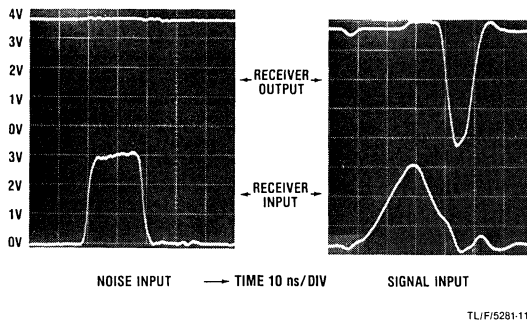


FIGURE 11. DS3662 Receiver Response

The performance of the transceiver under actual operating conditions is demonstrated in Figure 12. The oscillograms clearly show the capability of the DS3662 in real life situations. Here it is compared with the DS8834 under identical conditions. The transceivers drive a mini-computer bus (flat ribbon cable) 100 feet long, terminated at the far end with taps at various lengths for connecting to the receiver input. The cable is randomly folded to generate crosstalk between the various parts. In addition, a noise pulse induced on the signal line by driving an adja-

cent line with a pulse generator. As can be seen, the DS8834 device with fast rise and fall times on the driver output generates more crosstalk and its receiver easily responds to this crosstalk and to the externally induced noise (even though it has hysteresis!), limiting the useful length of the bus to less than 10 feet. In contrast, the DS3662's driver generates much less crosstalk and its receiver is immune to the induced noise even when the noise amplitude exceeds the signal amplitude as seen on the oscillogram at 50 feet.

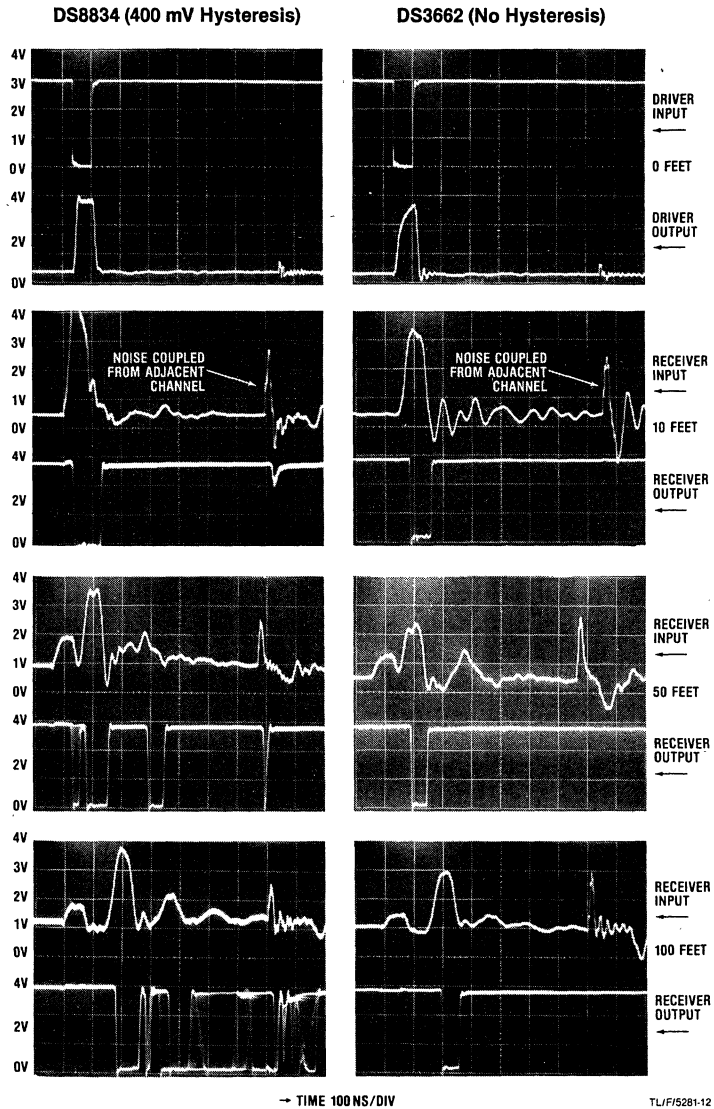


FIGURE 12. DS3662 vs Typical Schottky Transceiver—Real World Performance

WHAT NEXT?

Since crosstalk scales with the signal amplitude, reducing the signal swing has no effect on the noise immunity as long as the percentage noise margin remains the same. On the other hand, there are several advantages in having a lower signal swing. It reduces the drive current requirement of the driver thus reducing its output capacitance. Lower capacitive loading on the bus decreases its impedance reducing the drive requirement even further. Having a lower current drive not only reduces the power dissipated at the terminations but also allows better matching of the termination due to the increased line impedance. In the ideal limiting case the driver has negligible loading effect on the bus and thus allows perfect termination under all load conditions.

In practice however, there are some obvious limitations. The receiver thresholds have to be maintained within tighter limits at lower signal swings to maintain the same percentage noise margin. Also, the capacitive loading is difficult to reduce beyond a certain point, due to the diminishing return in the way of lower current rating, as the loaded bus impedance approaches the unloaded impedance. However, the capacitance of an open collector driver output can be reduced significantly by using a Schottky diode as shown in Figure 13. The diode isolates the driver capacitance when the output is disabled. Using reduced signal swings and precise receiver thresholds, such a transceiver can provide significant improvements in microcomputer bus performance.

CONCLUSION

A well designed bus transceiver goes a long way in improving the noise immunity of a single-ended TTL bus. Further improvements in bus performance may come from the use of reduced voltage swings and better transceiver designs for lower bus loading and tighter receiver threshold limits. Although such approaches may not be TTL compatible, the improvement in performance gained may indeed justify a new standard for bus transceivers.

REFERENCES

- 1) Bill Fowler, "Transmission Line Characteristics," National Semiconductor—Application Note 108, May 1974
- 2) A. Feller, H. P. Kaupp and J. J. Digiacom, "Crosstalk And Reflections In High Speed Digital Systems," proceedings—Fall Joint Computer Conference, pp. 511-525, 1965
- 3) R. V. Balakrishnan, "Bus Optimizer," National Semiconductor—Application Note 259, April 1981
- 4) David Montgomery, "Borrowing RF Techniques For Digital Design," Computer Design, pp. 207-217, May 1982
- 5) R. V. Balakrishnan, "Eliminating Crosstalk Over Long Distance Busing," Computer Design, pp. 155-162, March 1982

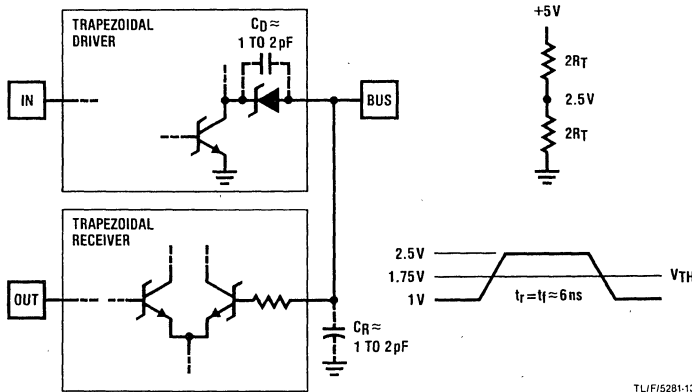


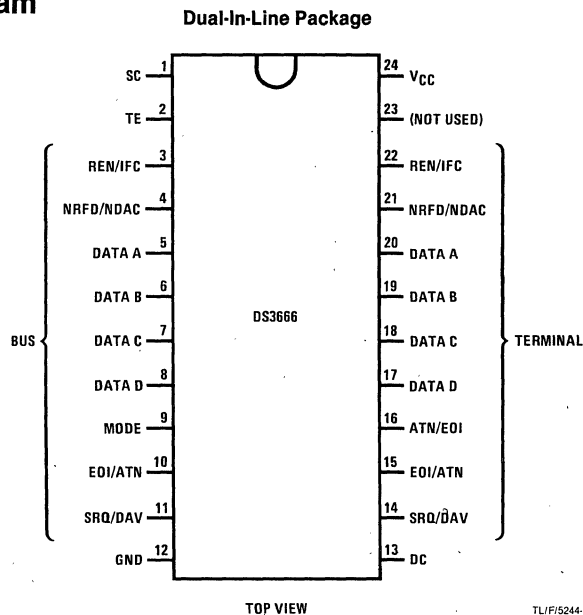
FIGURE 13. High Speed Bus Transceiver with Low Output Loading for Microcomputer Backplanes

DS3666 IEEE-488 GPIB Transceiver**General Description**

The DS3666 is a high-speed-Schottky 8-channel bi-directional transceiver designed to interface TTL/MOS logic to the IEEE Standard 488-1978 General Purpose Interface Bus. PNP inputs are used at all driver inputs for minimum loading, and hysteresis is provided at all receiver inputs for added noise margin. The IEEE-488 required bus termination is provided internally with an active turn-off feature which disconnects the termination from the bus when V_{CC} is removed. A power up/down protection circuit is included at all bus outputs to provide glitch-free operation during V_{CC} power up or down. Implementing the IEEE-488 bus interface is accomplished by connecting two DS3666 devices together using the expansion control inputs provided. Each device is assigned to 4 data channels and 4 management signal channels to achieve the 16-line format.

Features

- 8-channel bi-directional non-inverting transceivers
- Bi-directional control implemented with TRI-STATE® output design
- Meets IEEE Standard 488-1978
- High speed Schottky design
- Low power consumption
- High impedance PNP inputs (drivers)
- 500 mV (typ) input hysteresis (receivers)
- On-chip bus terminators
- No bus loading when V_{CC} is removed
- Power up/down protection (glitch-free)
- Mode control implements 2-device expansion for complete IEEE-488 interface configuration
- Accommodates multi-controller systems

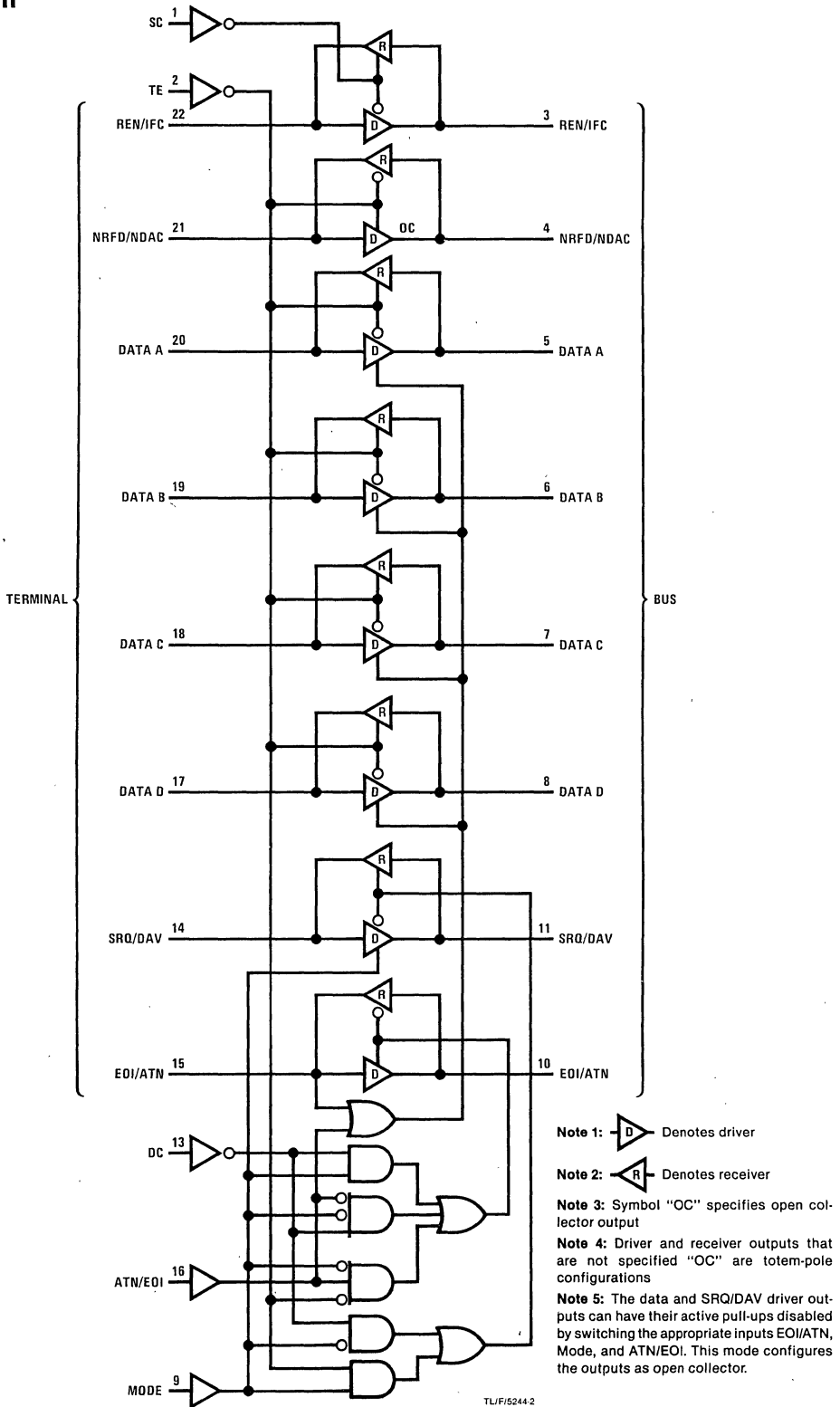
Connection Diagram

Order Number DS3666N
See NS Package N24C

Logic Diagram

DS3666

2



Device Truth Tables

TRANSCEIVER DIRECTION

Mode	Control Input Level				Transceiver Signal Direction				
	SC	TE	DC	ATN/EOI	REN/IFC	NRFD/NDAC	SRQ/DAV	EOI/ATN	Data
X	H	X	X	X	T				
X	L	X	X	X	R				
X	X	H	X	X		R			T
X	X	L	X	X		T			R
H	X	H	X	X			T		
H	X	L	X	X			R		
H	X	X	H	X				R	
H	X	X	L	X				T	
L	X	X	H	X			T		
L	X	X	L	X			R		
L	X	H	X	H				T	
L	X	L	X	H				R	
L	X	X	H	L				R	
L	X	X	L	L				T	

OUTPUT CONFIGURATION

Mode	Control Input Level			Transceiver Bus Output Configuration	
	ATN/EOI	EOI/ATN*	Data	SRQ/DAV	
X	H	H	Totem-Pole		
X	H	L	Totem-Pole		
X	L	H	Totem-Pole		
X	L	L	Open Collector		
H	X	X		Totem-Pole	
L	X	X		Open Collector	

H = High level input

L = Low level input

X = Don't care

T = Transmit, i.e., signal outputted to bus

R = Receive, i.e., signal outputted to terminal

*The EOI/ATN transceiver signal level is sensed for internal logic control of bus port data output configuration

Functional Description

The DS3666 is an 8-channel bi-directional transceiver with internal logic specifically configured to implement the IEEE-488 bus interface. Expansion logic is included so that two DS3666 devices may be interconnected to form the complete 16-line interface. This approach is equivalent to pairing the DS75160A and the DS75162A devices to implement the 16-line bus. The port connections to the bus lines have internal terminators, in accordance with the IEEE-488 Standard, that are deactivated when the device is powered down. This feature guarantees no bus loading when $V_{CC}=0V$. The bus port data outputs have a control mode that either enables or disables the active upper stage of the totem-pole configuration. When the upper stage is disabled, the data outputs operate as open collector outputs, which are necessary for parallel polling. In compliance with the system organization of the management signal lines, the NRFD/NDAC bus port output is a fixed open collector configuration. Also, the SRQ/DAV bus port output is configured so that the SRQ output is open collector in the expanded implementation of the device. Transceiver direction control is divided into three groups. The NRFD/NDAC and data lines are controlled by the TE input. The REN/IFC line is controlled by the SC input. And

the EOI/ATN and SRQ/DAV lines are controlled by the TE or DC input, depending on the expansion mode. A special case is the direction of the designated EOI line, which is a function of both the TE and DC inputs, as well as the logic level present on the ATN line.

TABLE OF SIGNAL LINE ABBREVIATIONS

Signal Line Classification	Mnemonic	Definition
Control Signals	DC	Direction Control
	TE	Talk Enable
	SC	System Controller
Data I/O Ports	Data A, Data B, Data C, Data D	Bi-directional Data Transceivers
Management Signals	ATN	Attention
	DAV	Data Valid
	EOI	End or Identify
	IFC	Interface Clear
	NDAC	Not Data Accepted
	NRFD	Not Ready for Data
	REN	Remote Enable
SRQ	Service Request	

IEEE-488 Interface Configuration Truth Tables (see Configuration Diagram)

MANAGEMENT SIGNALS

Control Input Level				Transceiver Signal Direction							
SC	TE	DC	ATN*	EOI	REN	IFC	SRQ	NRFD	NDAC	DAV	
H	H	H		R	T	T	T	R	R	T	
H	H	L		R	T	T	T	R	R	T	
H	L	H		R	T	T	T	R	R	T	
H	L	L		R	T	T	R	T	T	R	
L	H	H		R	R	R	T	R	R	T	
L	H	L		R	R	R	R	R	R	T	
L	L	H		R	R	R	T	T	T	R	
L	L	L		R	R	R	T	T	T	R	
X	H	X	H	T							
X	L	X	H	R							
X	X	H	L	R							
X	X	L	L	T							

DATA SIGNALS

Control Input Level			Data Transceivers	
ATN	EOI	TE	Direction	Bus Port Configuration
X	X	L	R	Input
H	H	H	T	Totem-Pole Output
H	L	H	T	Totem-Pole Output
L	H	H	T	Totem-Pole Output
L	L	H	T	Open Collector Output

H = High level input

L = Low level input

X = Don't care

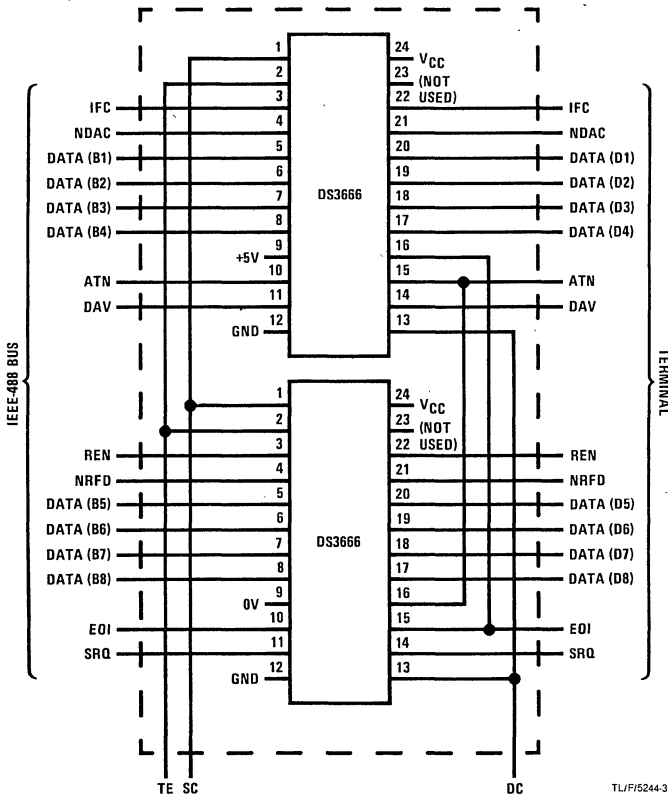
T = Transmit, i.e., signal outputted to bus

R = Receive, i.e., signal outputted to terminal

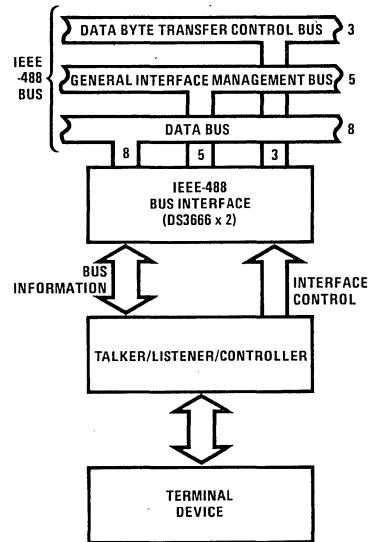
*The ATN signal level is sensed for internal multiplex control of EOI transmission direction logic

2

IEEE-488 Interface Configuration Implementation Using the DS3666



Terminal Interface Block Diagram



TLI/F5244-4

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Storage Temperature Range	-65°C to 150°C
Maximum Power Dissipation* at 25°C	
Molded Package	2005 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 16.0 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
V_{CC} , Supply Voltage	4.75	5.25	V
T_A , Ambient Temperature	0	70	°C
I_{OL} , Output Low Current: Bus		48	mA
Terminal		16	mA

Electrical Characteristics (Notes 2 and 3)

Parameter		Conditions	Min	Typ	Max	Units	
V_{IH}	High-Level Input Voltage		2			V	
V_{IL}	Low-Level Input Voltage				0.8	V	
V_{IK}	Input Clamp Voltage	$I_I = -18$ mA		-0.8	-1.5	V	
V_{HYS}	Input Hysteresis	Bus	400	500		mV	
V_{OH}	High-Level Output Voltage	Terminal	$I_{OH} = -800$ μ A	2.7	3.5	V	
		Bus (Note 5)	$I_{OH} = -5.2$ mA	2.5	3.4		
V_{OL}	Low-Level Output Voltage	Terminal	$I_{OL} = 16$ mA		0.3	0.5	V
		Bus	$I_{OL} = 48$ mA		0.4	0.5	
I_{IH}	High-Level Input Current	Terminal and Control Inputs	$V_I = 5.5$ V		0.2	100	μ A
			$V_I = 2.7$ V		0.1	20	
I_{IL}	Low-Level Input Current	$V_I = 0.5$ V		-10	-100	μ A	
V_{BIAS}	Terminator Bias Voltage at Bus Port	Driver Disabled	$I_{I(bus)} = 0$ (No Load)	2.5	3.0	3.7	V
I_{LOAD}	Terminator Bus Loading Current	Bus	Driver Disabled	$V_{I(bus)} = -1.5$ V to 0.4 V	-1.3		mA
			Driver Disabled	$V_{I(bus)} = 0.4$ V to 2.5 V	0	-3.2	
			Driver Disabled	$V_{I(bus)} = 2.5$ V to 3.7 V		2.5	
			Driver Disabled	$V_{I(bus)} = 3.7$ V to 5 V	0	2.5	
			Driver Disabled	$V_{I(bus)} = 5$ V to 5.5 V	0.7	2.5	
			$V_{CC} = 0$, $V_{I(bus)} = 0$ V to 2.5 V			40	μ A
I_{OS}	Short-Circuit Output Current	Terminal	$V_I = 2$ V, $V_O = 0$ V (Note 4)	-15	-35	-75	mA
		Bus (Note 5)		-35	-75	-150	
I_{CC}	Supply Current		$V_I = 0.8$ V, SC = 2.0 V, TE = 2.0 V, DC = 2.0 V, Mode = 2.0 V, ATN/EOI = 2.0 V		90	135	mA
C_{IN}	Bus-Port Capacitance	Bus	$V_{CC} = 5$ V or 0 V, $V_I = 0$ V to 2 V, $f = 1$ MHz		20	30	pF

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0$ V.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max or min are so classified on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: This characteristic does not apply to the NRFD/NDAC bus output since it is open collector.

Switching Characteristics $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$ (Note 1)

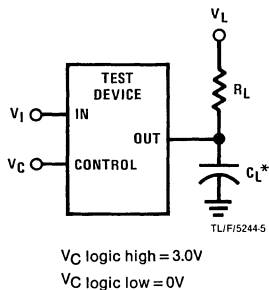
	Parameter	From	To	Conditions	Min	Typ	Max	Units
t_{PLH}	Propagation Delay Time, Low to High Level Output	Terminal	Bus	$V_L = 2.3V$ $R_L = 38.3\Omega$ $C_L = 30 pF$ <i>Figure 1</i>		10	20	ns
t_{PHL}	Propagation Delay Time, High to Low Level Output					14	20	
t_{PLH}	Propagation Delay Time, Low to High Level Output	Bus	Terminal	$V_L = 5.0V$ $R_L = 240\Omega$ $C_L = 30 pF$ <i>Figure 2</i>		14	20	ns
t_{PHL}	Propagation Delay Time, High to Low Level Output					10	20	
t_{PZH}	Output Enable Time to High Level	Control Inputs (Note 2) (Note 3)	Bus	$V_I = 3.0V$ $V_L = 0V$ $R_L = 480\Omega$ $C_L = 15 pF$ <i>Figure 1</i>		23	40	ns
t_{PHZ}	Output Disable Time from High Level					15	27	
t_{PZL}	Output Enable Time to Low Level					28	48	ns
t_{PLZ}	Output Disable Time from Low Level					17	35	
t_{PZH}	Output Enable Time to High Level	Control Inputs (Note 2) (Note 3)	Terminal	$V_I = 3.0V$ $V_L = 0V$ $R_L = 3 k\Omega$ $C_L = 15 pF$ <i>Figure 1</i>		18	45	ns
t_{PHZ}	Output Disable Time from High Level					22	33	
t_{PZL}	Output Enable Time to Low Level					28	56	ns
t_{PLZ}	Output Disable Time from Low Level					20	35	
t_{PZH}	Output Pull-Up Enable Time	ATN/EOI Input (Note 2)	Bus Data Outputs	$V_I = 3V$ $V_L = 0V$ $R_L = 480\Omega$ $C_L = 15 pF$ <i>Figure 1</i>		10	20	ns
t_{PHZ}	Output Pull-Up Disable Time					10	20	

Note 1: Typical values are for $V_{CC} = 5.0V$ and $T_A = 25^\circ C$ and are meant for reference only.

Note 2: Refer to functional truth table for control input definition.

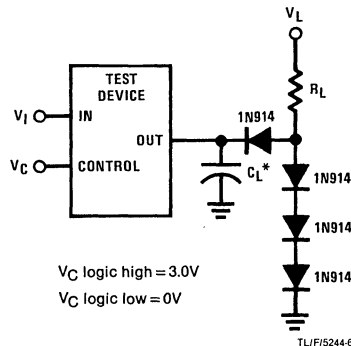
Note 3: Test configuration should be connected to only one transceiver at a time due to the high current stress caused by the V_I voltage source when the output connected to that input becomes active.

Switching Load Configurations



* C_L includes jig and probe capacitance

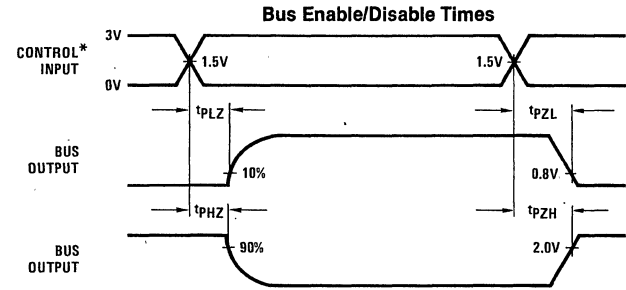
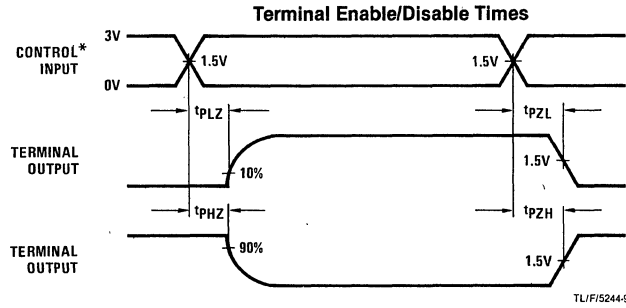
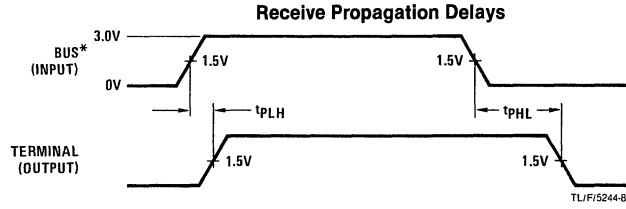
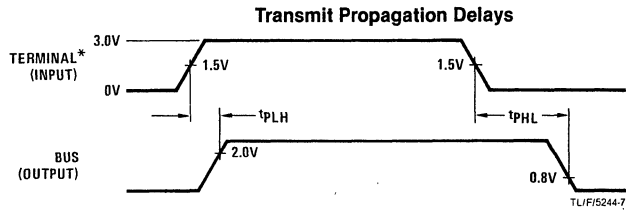
FIGURE 1



* C_L includes jig and probe capacitance

FIGURE 2

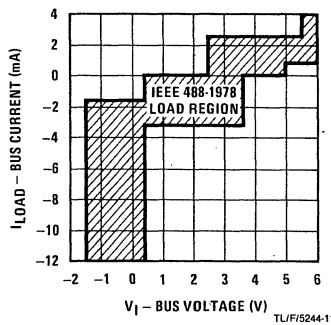
Switching Waveforms



* Input signal: $f = 1.0$ MHz, 50% duty cycle, $t_r = t_f \leq 5$ ns

Performance Characteristics

Bus Port Load Characteristic



Refer to Electrical Characteristics Table

IEEE-488 Specification Summary

Logic Nomenclature. When referring to the IEEE-488 specification publication, the following logic conventions are used:

- 1) A "true" condition corresponds to a logic low signal level.
- 2) A "false" condition corresponds to a logic high signal level.

Bus Specification. The IEEE-488 bus is comprised of 16 signal lines intended for digital data exchange at a maximum rate of 1 Mbaud and for a maximum transmission path length of 20 meters.

Terminal Devices. The IEEE-488 bus will support a maximum of 15 interconnected devices. These devices may be configured in four different modes of operation:

- 1) Talk only (e.g., counter)
- 2) Listen only (e.g., printer)
- 3) Listen and talk (e.g., multimeter)
- 4) Listen, talk, and control (e.g., calculator)

Data Bus. The data bus has 8 signal lines, denoted DIO₁ through DIO₈. These lines carry data and interface messages in a bi-directional asynchronous, bit parallel, byte serial form.

Data Byte Transfer Control Bus. These 3 signal lines are used to control the transfer of data bytes across the data bus lines.

- 1) NRFD (Not Ready for Data). This signal originates from a listen device and indicates to a talker that a listen device is not ready to accept data.

- 2) DAV (Data Valid). This signal originates from a talker device and indicates to a listen device that data present on the data bus is valid.
- 3) NDAC (Not Data Accepted). This signal originates from a listen device and indicates to a talker device that data on the data bus has not been accepted.

General Interface Management Bus. These 5 signal lines provide general management of all bus operations.

- 1) ATN (Attention). This signal originates from a controller device and indicates to other devices on the bus how the data bus information is to be interpreted.
- 2) IFC (Interface Clear). This signal originates from a controller device and causes all interface logic to be set to a known state.
- 3) REN (Remote Enable). This signal originates from a controller device and is used in conjunction with other messages to tell a remote device which of two sources of information is to be used. The source is designated as being remote or local.
- 4) SRQ (Service Request). This signal is generated by a remote device to indicate to the controller device a need for attention.
- 5) EOI (End or Identify). This signal is generated by a talker device to indicate the end of a multibyte transfer. This signal may also originate from a controller, in conjunction with ATN to execute a polling sequence.

DS3667 TRI-STATE® Bidirectional Transceiver

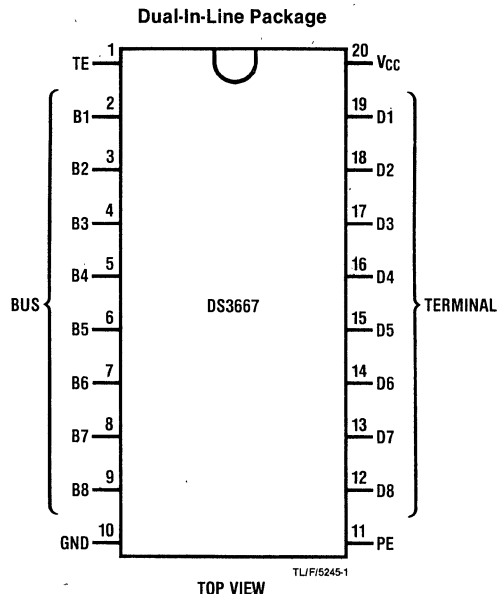
General Description

The DS3667 is a high speed Schottky 8-channel bidirectional transceiver designed for digital information and communication systems. Pin selectable totem-pole/open collector outputs are provided at all driver outputs. This feature, together with the Dumb Mode which puts both driver and receiver outputs in TRI-STATE at the same time, means higher flexibility of system design. PNP inputs are used at all driver inputs for minimum loading, and hysteresis is provided at all receiver inputs for added noise margin. A power up/down protection circuit is included at all outputs to provide glitch-free operation during V_{CC} power up or down.

Features

- 8-channel bidirectional non-inverting transceivers
- Bidirectional control implemented with TRI-STATE output design
- High speed Schottky design
- Low power consumption
- High impedance PNP inputs (drivers)
- Pin selectable totem-pole/open collector outputs (drivers)
- 500 mV (typ) input hysteresis (receivers)
- Power up/down protection (glitch-free)
- Dumb Mode capability

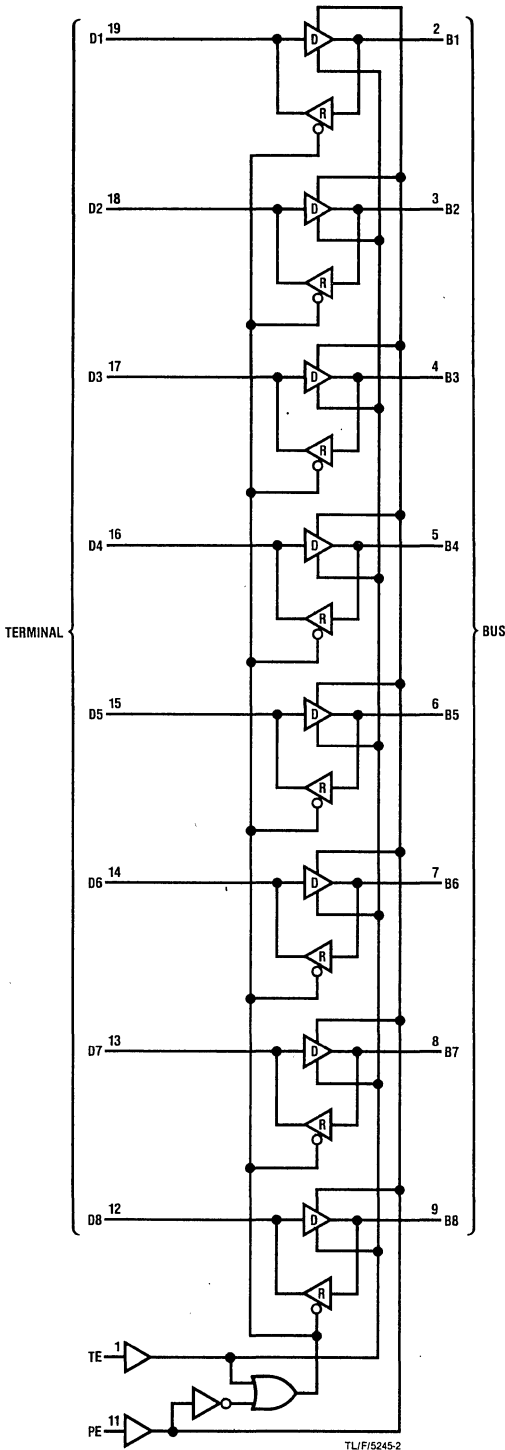
Connection Diagram



Order Number DS3667N
See NS Package N20A

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Logic Diagram



Functional Truth Table

Control Input Level		Data Transceivers		
TE	PE	Mode	Bus Port	Terminal Port
H	H	T	Totem-Pole Output	Input
H	L	T	Open Collector Output	Input
L	H	R	Input	Output
L	L	D	TRI-STATE	TRI-STATE

H: High Level Input
 L: Low Level Input
 T: Transmitting Mode
 R: Receiving Mode
 D: Dumb Mode

Note 1: Denotes driver

Note 2: Denotes receiver

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Storage Temperature Range	-65°C to 150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1832 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 14.7 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
V_{CC} , Supply Voltage	4.75	5.25	V
T_A , Ambient Temperature	0	70	°C
I_{OL} , Output Low Current		48	mA
Bus		16	mA
Terminal			

Electrical Characteristics (Notes 2 and 3)

Parameter		Conditions		Min	Typ	Max	Units
V_{IH}	High Level Input Voltage			2			V
V_{IL}	Low Level Input Voltage					0.8	V
V_{IK}	Input Clamp Voltage		$I_I = -18$ mA		-0.8	-1.5	V
V_{HYS}	Input Hysteresis	Bus		400	500		mV
V_{OH}	High Level Output Voltage	Terminal	$I_{OH} = -800$ μ A	2.7	3.5		V
		Bus	$I_{OH} = -5.2$ mA	2.5	3.4		
V_{OL}	Low Level Output Voltage	Terminal	$I_{OL} = 16$ mA		0.3	0.5	V
		Bus	$I_{OL} = 48$ mA		0.4	0.5	
I_{IH}	High Level Input Current	TE, PE	$V_I = 5.5$ V		0.2	100	μ A
			$V_I = 2.7$ V		0.1	20	
		Terminal and Bus	$V_I = 4$ V			200	
I_{IL}	Low Level Input Current	Terminal and TE, PE	$V_I = 0.5$ V		-10	-100	μ A
		Bus			-0.4	-1.0	mA
I_{OS}	Short Circuit Output Current	Terminal	$V_I = 2$ V, $V_O = 0$ V (Note 4)	-15	-35	-75	mA
		Bus		-50	-120	-200	
I_{CC}	Supply Current	Transmit, TE = 2V, PE = 2V, $V_I = 0.8$ V			75	100	mA
		Receive, TE = 0.8V, PE = 2V, $V_I = 0.8$ V			65	90	
C_{IN}	Bus-Port Capacitance	Bus	$V_{CC} = 0$ V, $V_I = 0$ V, $f = 10$ kHz (Note 5)		20	30	pF

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0$ V.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max or min are so classified on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: This parameter is guaranteed by design. It is not a tested parameter.

Switching Characteristics $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$ (Note 1)

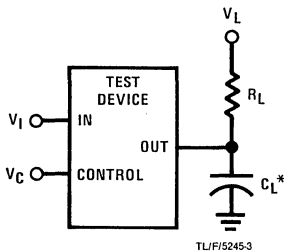
Parameter	From	To	Conditions	Min	Typ	Max	Units
t_{PLH} Propagation Delay Time, Low to High Level Output	Terminal	Bus	$V_L = 2.3V$ $R_L = 38.3\Omega$ $C_L = 30\text{ pF}$ <i>Figure 1</i>		10	20	ns
t_{PHL} Propagation Delay Time, High to Low Level Output					14	20	ns
t_{PLH} Propagation Delay Time, Low to High Level Output	Bus	Terminal	$V_L = 5.0V$ $R_L = 240\Omega$ $C_L = 30\text{ pF}$ <i>Figure 2</i>		15	20	ns
t_{PHL} Propagation Delay Time, High to Low Level Output					10	20	ns
t_{PZH} Output Enable Time to High Level	TE (Note 2) (Note 3)	Bus	$V_I = 3.0V$ $V_L = 0V$ $R_L = 480\Omega$ $C_L = 15\text{ pF}$ <i>Figure 1</i>		19	30	ns
t_{PHZ} Output Disable Time from High Level					15	20	ns
t_{PZL} Output Enable Time to Low Level					24	40	ns
t_{PLZ} Output Disable Time from Low Level					17	30	ns
t_{PZH} Output Enable Time to High Level	TE, PE (Note 2) (Note 3)	Terminal	$V_I = 3.0V$ $V_L = 0V$ $R_L = 3\text{ k}\Omega$ $C_L = 15\text{ pF}$ <i>Figure 1</i>		19	35	ns
t_{PHZ} Output Disable Time from High Level					17	25	ns
t_{PZL} Output Enable Time to Low Level					27	40	ns
t_{PLZ} Output Disable Time from Low Level					17	30	ns
t_{pZH} Output Pull-Up Enable Time	PE (Note 2)	Bus	$V_I = 3V$ $V_L = 0V$ $R_L = 480\Omega$ $C_L = 15\text{ pF}$ <i>Figure 1</i>		10	20	ns
t_{pHZ} Output Pull-Up Disable Time					10	20	ns

Note 1: All typical values are for $T_A = 25^\circ C$, $V_{CC} = 5V$.

Note 2: Refer to Functional Truth Table for control input definition.

Note 3: Test configuration should be connected to only one transceiver at a time due to the high current stress caused by the V_I voltage source when the output connected to that input becomes active.

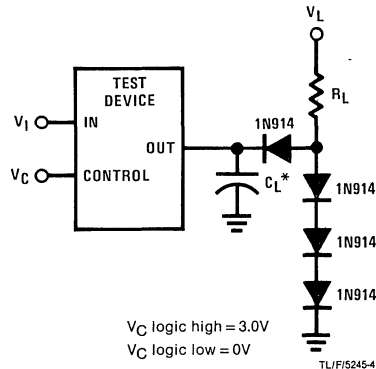
Switching Load Configurations



V_C logic high = 3.0V
 V_C logic low = 0V

* C_L includes jig and probe capacitance

FIGURE 1

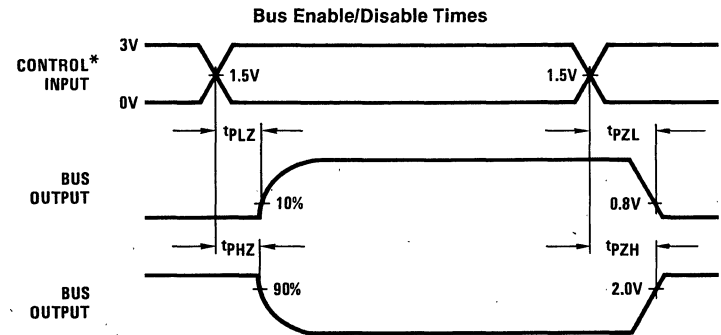
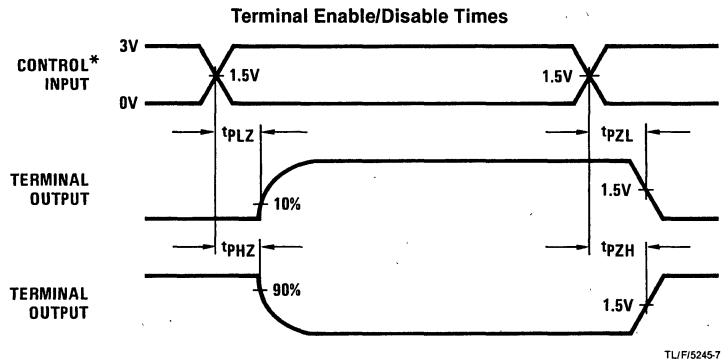
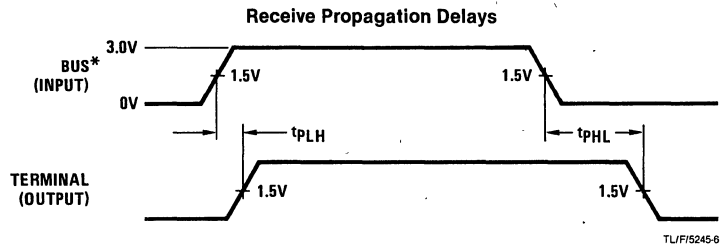
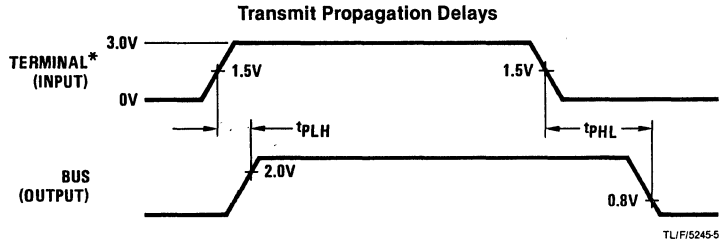


V_C logic high = 3.0V
 V_C logic low = 0V

* C_L includes jig and probe capacitance

FIGURE 2

Switching Waveforms



* Input signal: $f = 1.0$ MHz, 50% duty cycle, $t_r = t_f \leq 5$ ns

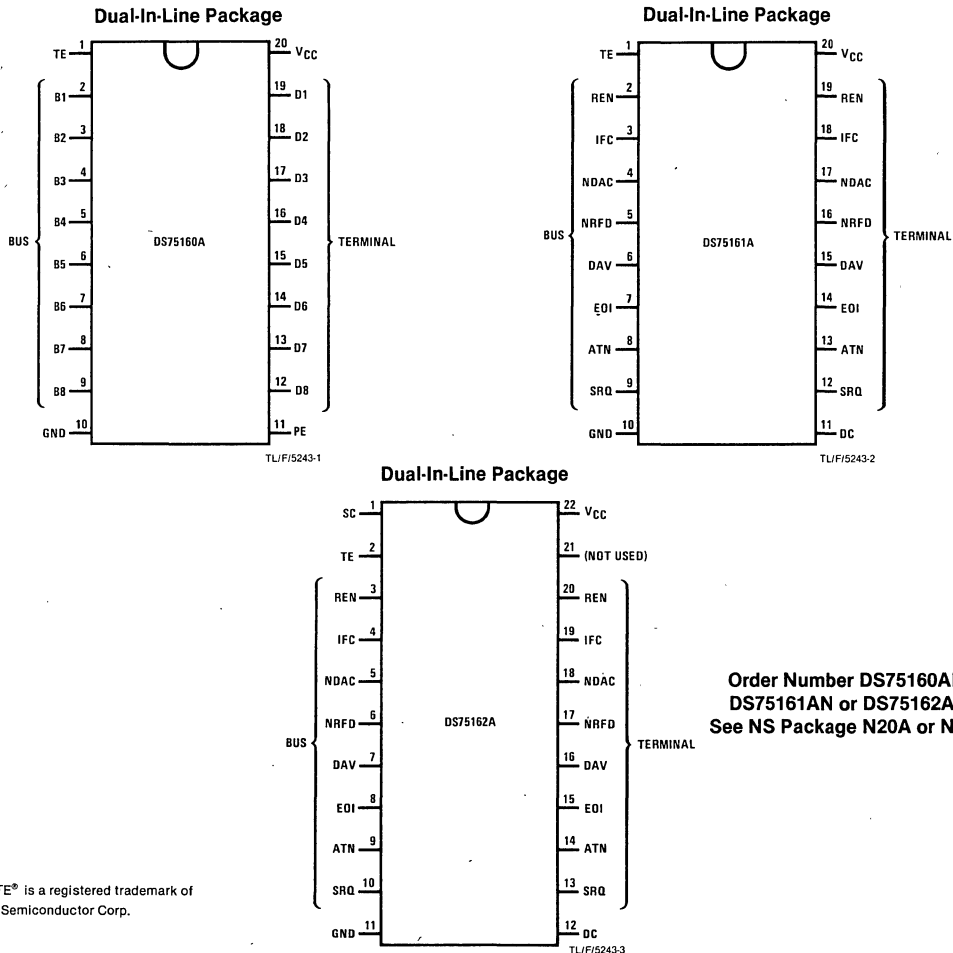
DS75160A/DS75161A/DS75162A IEEE-488 GPIB Transceivers
General Description

This family of high-speed-Schottky 8-channel bi-directional transceivers is designed to interface TTL/MOS logic to the IEEE Standard 488-1978 General Purpose Interface Bus (GPIB). PNP inputs are used at all driver inputs for minimum loading, and hysteresis is provided at all receiver inputs for added noise margin. The IEEE-488 required bus termination is provided internally with an active turn-off feature which disconnects the termination from the bus when V_{CC} is removed. A power up/down protection circuit is included at all bus outputs to provide glitch-free operation during V_{CC} power up or down.

The General Purpose Interface Bus is comprised of 16 signal lines—8 for data and 8 for interface management. The data lines are always implemented with DS75160A, and the management lines are either implemented with DS75161A in a single-controller system, or with DS75162A in a multi-controller system.

Features

- 8-channel bi-directional non-inverting transceivers
- Bi-directional control implemented with TRI-STATE® output design
- Meets IEEE Standard 488-1978
- High-speed Schottky design
- Low power consumption
- High impedance PNP inputs (drivers)
- 500 mV (typ) input hysteresis (receivers)
- On-chip bus terminators
- No bus loading when V_{CC} is removed
- Power up/down protection (glitch-free)
- Pin selectable open collector mode on DS75160A driver outputs
- Accommodates multi-controller systems

2
Connection Diagrams (Top Views)


**Order Number DS75160AN,
DS75161AN or DS75162AN
See NS Package N20A or N22A**

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Functional Description

DS75160A

This device is an 8-channel bi-directional transceiver with one common direction control input, denoted TE. When used to implement the IEEE-488 bus, this device is connected to the eight data bus lines, designated DIO₁-DIO₈. The port connections to the bus lines have internal terminators, in accordance with the IEEE-488 Standard, that are deactivated when the device is powered down. This feature guarantees no bus loading when V_{CC} = 0V. The bus port outputs also have a control mode that either enables or disables the active upper stage of the totem-pole configuration. When this control input, denoted PE, is in the high state, the bus outputs operate in the high-speed totem-pole mode. When PE is in the low state, the bus outputs operate as open collector outputs which are necessary for parallel polling.

DS75161A

This device is also an 8-channel bi-directional transceiver which is specifically configured to implement the eight management signal lines of the IEEE-488 bus. This device, paired with the DS75160A, forms the complete 16-line interface between the IEEE-488 bus and a single controller instrumentation system. In compliance with the system organization of the management signal lines, the SRQ, NDAC, and NRFD bus port outputs are open collector. In contrast to the DS75160A, these open collector outputs are a fixed configuration. The direction control is divided into three groups. The DAV, NDAC, and NRFD transceiver directions are controlled by the TE input. The ATN, SRQ, REN, and IFC transceiver directions are controlled by the DC input. The EOI transceiver direction is a function of both the TE and DC inputs, as well as the logic level present on the ATN channel. The port connections to the bus lines have internal terminators identical to the DS75160A.

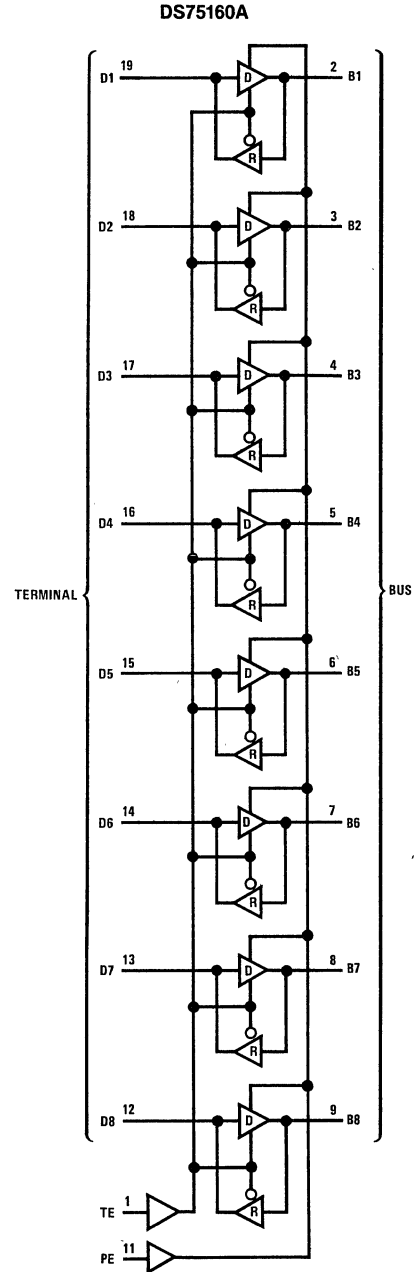
DS75162A

This device is identical to the DS75161A, except that an additional direction control input is provided, denoted SC. The SC input controls the direction of the REN and IFC transceivers that are normally controlled by the DC input on the DS75161A. This additional control function is instrumental in implementing multiple controller systems.

TABLE OF SIGNAL LINE ABBREVIATIONS

Signal Line Classification	Mnemonic	Definition	Device
Control Signals	DC	Direction Control	DS75161A/DS75162A
	PE	Pull-Up Enable	DS75160A
	TE	Talk Enable	All
	SC	System Controller	DS75162A
	Data I/O Ports	B1-B8	Bus Side of Device
	D1-D8	Terminal Side of Device	
Management Signals	ATN	Attention	DS75161A/DS75162A
	DAV	Data Valid	
	EOI	End or Identify	
	IFC	Interface Clear	
	NDAC	Not Data Accepted	
	NRFD	Not Ready for Data	
	REN	Remote Enable	
SRQ	Service Request		

Logic Diagrams



TL/F/5243-4

Note 1: Denotes driver

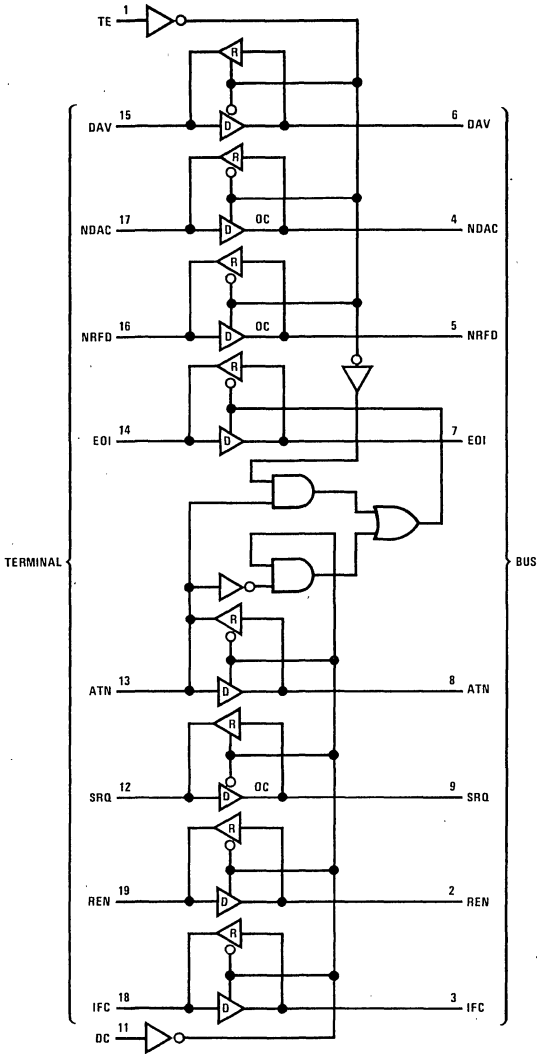
Note 2: Denotes receiver

Note 3: Driver and receiver outputs are totem-pole configurations

Note 4: The driver outputs of DS75160A can have their active pull-ups disabled by switching the PE input (pin 11) to the logic low state. This mode configures the outputs as open collector.

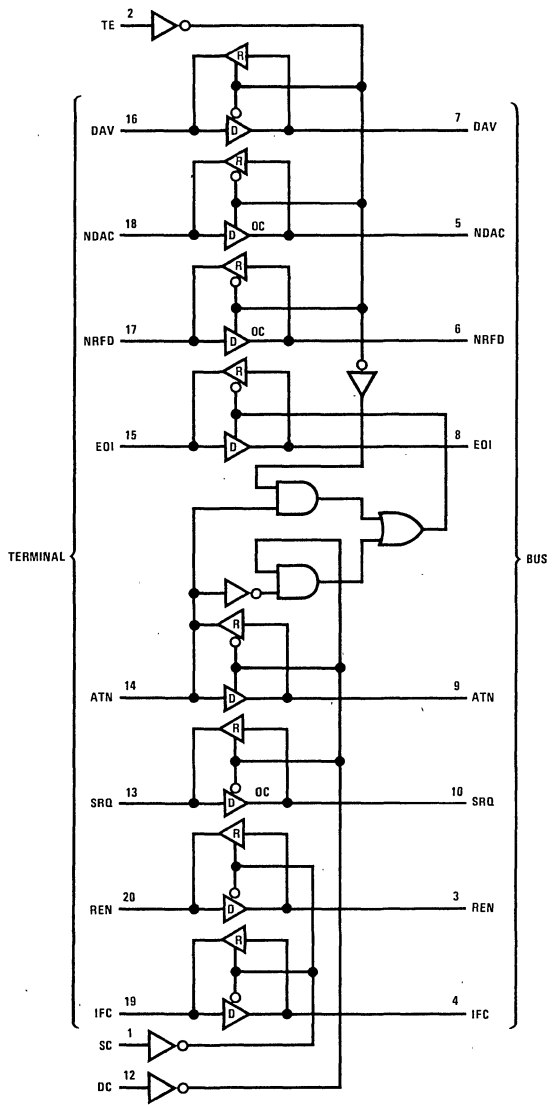
Logic Diagrams (Continued)

DS75161A





TL/F/5243-5

DS75162A



TL/F/5243-6

Note 1:  Denotes driver

Note 2:  Denotes receiver

Note 3: Symbol "OC" specifies open collector output

Note 4: Driver and receiver outputs that are not specified "OC" are totem-pole configurations

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Storage Temperature Range	-65°C to 150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1897 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
V_{CC} , Supply Voltage	4.75	5.25	V
T_A , Ambient Temperature	0	70	°C
I_{OL} , Output Low Current		48	mA
Bus		16	mA
Terminal			

*Derate molded package 15.2 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

Parameter		Conditions	Min	Typ	Max	Units		
V_{IH}	High-Level Input Voltage		2			V		
V_{IL}	Low-Level Input Voltage				0.8	V		
V_{IK}	Input Clamp Voltage	$I_I = -18$ mA		-0.8	-1.5	V		
V_{HYS}	Input Hysteresis	Bus	400	500		mV		
V_{OH}	High-Level Output Voltage	Terminal	$I_{OH} = -800$ μ A	2.7	3.5	V		
		Bus (Note 5)	$I_{OH} = -5.2$ mA	2.5	3.4			
V_{OL}	Low-Level Output Voltage	Terminal	$I_{OL} = 16$ mA		0.3	0.5	V	
		Bus	$I_{OL} = 48$ mA		0.4	0.5		
I_{IH}	High-Level Input Current	Terminal and TE, PE, DC, SC Inputs	$V_I = 5.5$ V $V_I = 2.7$ V	0.2 0.1	100 20	μ A		
I_{IL}	Low-Level Input Current		$V_I = 0.5$ V	-10	-100	μ A		
V_{BIAS}	Terminator Bias Voltage at Bus Port	Driver Disabled	$I_{I(bus)} = 0$ (No Load)	2.5	3.0	3.7	V	
I_{LOAD}	Terminator Bus Loading Current	Bus	Driver Disabled	$V_{I(bus)} = -1.5$ V to 0.4V	-1.3		mA	
				$V_{I(bus)} = 0.4$ V to 2.5V	0	-3.2		
				$V_{I(bus)} = 2.5$ V to 3.7V		2.5 -3.2		
				$V_{I(bus)} = 3.7$ V to 5V	0	2.5		
				$V_{I(bus)} = 5$ V to 5.5V	0.7	2.5		
		$V_{CC} = 0$, $V_{I(bus)} = 0$ V to 2.5V			40	μ A		
I_{OS}	Short-Circuit Output Current	Terminal	$V_I = 2$ V, $V_O = 0$ V (Note 4)	-15	-35	-75	mA	
		Bus (Note 5)		-35	-75	-150		
I_{CC}	Supply Current	DS75160A	Transmit, TE = 2V, PE = 2V, $V_I = 0.8$ V		85	125	mA	
			Receive, TE = 0.8V, PE = 2V, $V_I = 0.8$ V		70	100		
			DS75161A	TE = 0.8V, DC = 0.8V, $V_I = 0.8$ V		84		125
			DS75162A	TE = 0.8V, DC = 0.8V, SC = 2V, $V_I = 0.8$ V		85		125
C_{IN}	Bus-Port Capacitance	Bus	$V_{CC} = 5$ V or 0V, $V_I = 0$ V to 2V, $f = 1$ MHz		20	30	pF	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25$ °C and $V_{CC} = 5.0$ V.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max or min are so classified on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: This characteristic does not apply to outputs on DS75161A and DS75162A that are open collector.

Switching Characteristics $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$ (Note 1)

DS75160A/DS75161A/
DS75162A

2

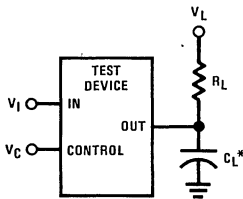
Parameter	From	To	Conditions	DS75160A			DS75161A			DS75162A			Units
				Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{PLH} Propagation Delay Time, Low to High Level Output	Terminal	Bus	$V_L = 2.3V$ $R_L = 38.3\Omega$ $C_L = 30 pF$ <i>Figure 1</i>		10	20		10	20		10	20	ns
t_{PHL} Propagation Delay Time, High to Low Level Output					14	20		14	20		14	20	ns
t_{PLH} Propagation Delay Time, Low to High Level Output	Bus	Terminal	$V_L = 5.0V$ $R_L = 240\Omega$ $C_L = 30 pF$ <i>Figure 2</i>		14	20		14	20		14	20	ns
t_{PHL} Propagation Delay Time, High to Low Level Output					10	20		10	20		10	20	ns
t_{PZH} Output Enable Time to High Level	TE, DC, or SC (Note 2) (Note 3)	Bus	$V_I = 3.0V$ $V_L = 0V$ $R_L = 480\Omega$ $C_L = 15 pF$ <i>Figure 1</i>		19	32		23	40		23	40	ns
t_{PHZ} Output Disable Time from High Level					15	22		15	25		15	25	ns
t_{PZL} Output Enable Time to Low Level					24	35		28	48		28	48	ns
t_{PLZ} Output Disable Time from Low Level					17	25		17	27		17	27	ns
t_{PZH} Output Enable Time to High Level	TE, DC, or SC (Note 2) (Note 3)	Terminal	$V_I = 3.0V$ $V_L = 0V$ $R_L = 3 k\Omega$ $C_L = 15 pF$ <i>Figure 1</i>		17	33		18	40		18	40	ns
t_{PHZ} Output Disable Time from High Level					15	25		22	33		22	33	ns
t_{PZL} Output Enable Time to Low Level					25	39		28	52		28	52	ns
t_{PLZ} Output Disable Time from Low Level					15	27		20	35		20	35	ns
t_{PZH} Output Pull-Up Enable Time (DS75160A Only)	PE (Note 2)	Bus	$V_I = 3V$ $V_L = 0V$ $R_L = 480\Omega$ $C_L = 15 pF$ <i>Figure 1</i>		10	17		NA			NA		ns
t_{PHZ} Output Pull-Up Disable Time (DS75160A Only)					10	15		NA			NA		ns

Note 1: Typical values are for $V_{CC} = 5.0V$ and $T_A = 25^\circ C$ and are for reference only.

Note 2: Refer to Functional Truth Tables for control input definition.

Note 3: Test configuration should be connected to only one transceiver at a time due to the high current stress caused by the V_I voltage source when the output connected to that input becomes active.

Switching Load Configurations

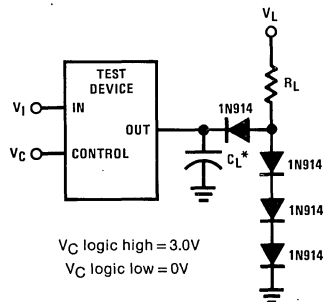


V_C logic high = 3.0V
 V_C logic low = 0V

* C_L includes jig and probe capacitance

FIGURE 1

TL/F/5243-7



V_C logic high = 3.0V
 V_C logic low = 0V

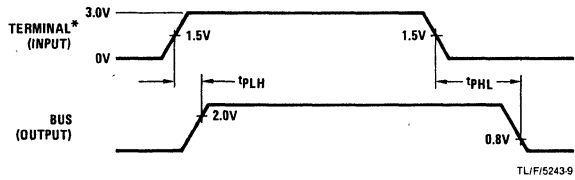
* C_L includes jig and probe capacitance

FIGURE 2

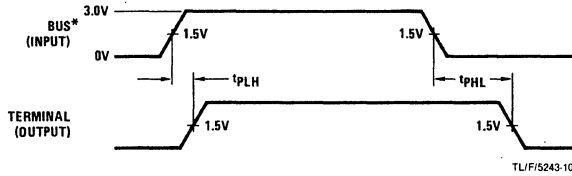
TL/F/5243-8

Switching Waveforms

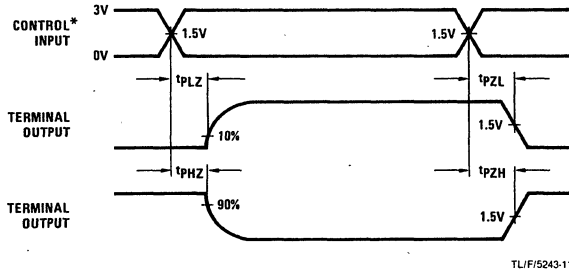
Transmit Propagation Delays



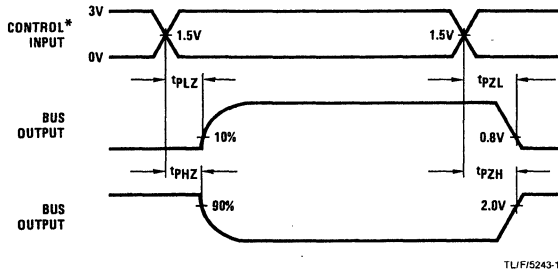
Receive Propagation Delays



Terminal Enable/Disable Times



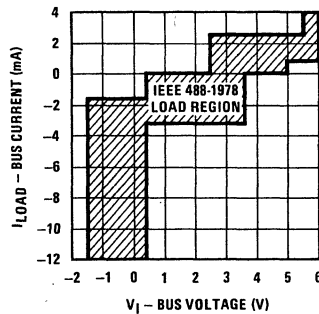
Bus Enable/Disable Times



* Input signal: $f = 1.0$ MHz, 50% duty cycle, $t_r = t_f \leq 5$ ns

Performance Characteristics

Bus Port Load Characteristic



Refer to Electrical Characteristics table

TL/F/5243-13

Functional Truth Tables

DS75160A

Control Input Level		Data Transceivers	
TE	PE	Direction	Bus Port Configuration
H	H	T	Totem-Pole Output
H	L	T	Open Collector Output
L	X	R	Input

DS75161A

Control Input Level			Transceiver Signal Direction							
TE	DC	ATN*	EOI	REN	IFC	SRQ	NRFD	NDAC	DAV	
H	H		R		R	R	T	R	R	T
H	L		T		T	T	R	R	R	T
L	H		R		R	R	T	T	T	R
L	L		T		T	T	R	T	T	R
H	X	H		T						
L	X	H		R						
X	H	L		R						
X	L	L		T						

DS75162A

Control Input Level				Transceiver Signal Direction							
SC	TE	DC	ATN*	EOI	REN	IFC	SRQ	NRFD	NDAC	DAV	
H	H	H		R		T	T	T	R	R	T
H	H	L		T		T	T	R	R	R	T
H	L	H		R		T	T	T	T	R	
H	L	L		T		T	T	R	T	T	R
L	H	H		R		R	R	T	R	R	T
L	H	L		T		R	R	R	R	R	T
L	L	H		R		R	R	T	T	T	R
L	L	L		T		R	R	R	T	T	R
X	H	X	H		T						
X	L	X	H		R						
X	X	H	L		R						
X	X	L	L		T						

H = High level input

L = Low level input

X = Don't care

T = Transmit, i.e., signal outputted to bus

R = Receive, i.e., signal outputted to terminal

* The ATN signal level is sensed for internal multiplex control of EOI transmission direction logic

DS7640/DS8640 Quad NOR Unified Bus Receiver

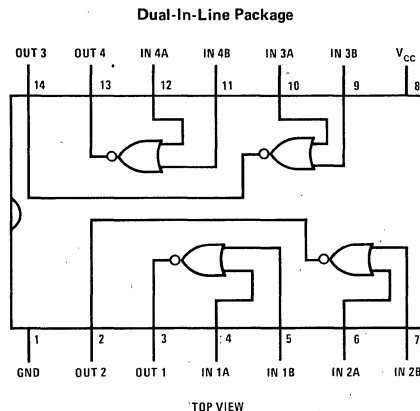
General Description

The DS7640 and DS8640 are quad 2-input receivers designed for use in bus organized data transmission systems interconnected by terminated 120Ω impedance lines. The external termination is intended to be 180Ω resistor from the bus to the +5V logic supply together with a 390Ω resistor from the bus to ground. The design employs a built-in input threshold providing substantial noise immunity. Low input current allows up to 27 driver/receiver pairs to utilize a common bus.

Features

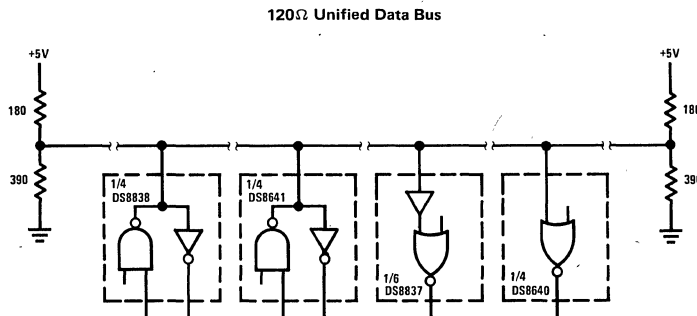
- Low input current with normal V_{CC} or $V_{CC} = 0V$ ($30\mu A$ typ)
- High noise immunity (1.1V typ)
- Temperature-insensitive input thresholds track bus logic levels
- TTL compatible output
- Matched, optimized noise immunity for "1" and "0" levels
- High speed (19 ns typ)

Connection Diagram



Order Number DS7640J, DS8640J
or DS8640N
See NS Package J14A or N14A

Typical Application



Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Input Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 8.7 mW/°C above 25°C; derate molded package 9.7 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7640	4.5	5.5	V
DS8640	4.75	5.25	V
Temperature (T _A)			
DS7640	-55	+125	°C
DS8640	0	+70	°C

Electrical Characteristics

The following apply for $V_{MIN} \leq V_{CC} \leq V_{MAX}$, $T_{MIN} \leq T_A \leq T_{MAX}$, unless otherwise specified (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH} High Level Input Threshold	V _{OUT} = V _{OL}	DS7640	1.80	1.50		V
		DS8640	1.70	1.50		V
V _{IL} Low Level Input Threshold	V _{OUT} = V _{OH}	DS7640		1.50	1.20	V
		DS8640		1.50	1.30	V
I _{IH} Maximum Input Current	V _{IN} = 4V	V _{CC} = V _{MAX}		30	80	μA
		V _{CC} = 0V		1.0	50	μA
I _{IL} Maximum Input Current	V _{IN} = 0.4V, V _{CC} = V _{MAX}		1.0	50	μA	
V _{OH} Output Voltage	I _{OH} = -400μA, V _{IN} = V _{IL}	2.4			V	
V _{OL} Output Voltage	I _{OL} = 16 mA, V _{IN} = V _{IH}		0.25	0.4	V	
I _{OS} Output Short Circuit Current	V _{IN} = 0.5V, V _{OS} = 0V, V _{CC} = V _{MAX} , (Note 4)	-18		-55	mA	
I _{CC} Power Supply Current	V _{IN} = 4V, (Per Package)		25	40	mA	

Switching Characteristics T_A = 25°C, nominal power supplies unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t _{pd} Propagation Delays	(Notes 5 and 6)	Input to Logic "1" Output	10	23	35	ns
		Input to Logic "0" Output	10	15	30	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7640 and across the 0°C to +70°C range for the DS8640. All typical values are for T_A = 25°C and V_{CC} = 5V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: Fan-out of 10 load, C_{LOAD} = 15 pF total, measured from V_{IN} = 1.5V to V_{OUT} = 1.5V, V_{IN} = 0V to 3V pulse.

Note 6: Apply for V_{CC} = 5V, T_A = 25°C.

DS7641/DS8641 Quad Unified Bus Transceiver

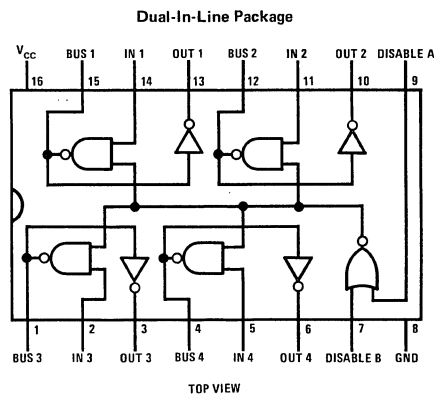
General Description

The DS7641 and DS8641 are quad high speed drivers/receivers designed for use in bus organized data transmission systems interconnected by terminated 120Ω impedance lines. The external termination is intended to be a 180Ω resistor from the bus to the +5V logic supply together with a 390Ω resistor from the bus to ground. The bus can be terminated at one or both ends. Low bus pin current allows up to 27 driver/receiver pairs to utilize a common bus. The bus loading is unchanged when $V_{CC} = 0V$. The receivers incorporate tight thresholds for better bus noise immunity. One two-input NOR gate is included to disable all drivers in a package simultaneously.

Features

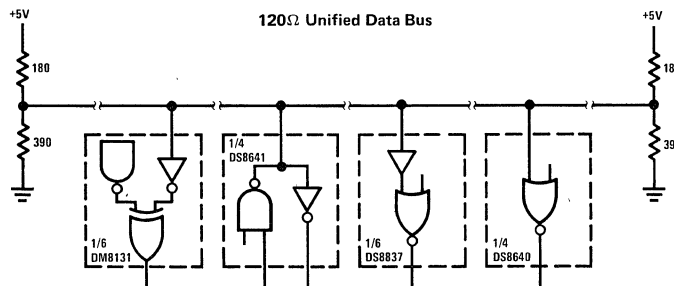
- 4 separate driver/receiver pairs per package
- Guaranteed minimum bus noise immunity of 0.6V, 1.1V typ
- Temperature insensitive receiver thresholds track bus logic levels
- $30\mu A$ typical bus terminal current with normal V_{CC} or with $V_{CC} = 0V$
- Open collector driver output allows wire-OR connection
- High speed
- Series 74 TTL compatible driver and disable inputs and receiver outputs

Connection Diagram



Order Number DS7641J, DS8641J or DS8641N
See NS Package J16A or N16A

Typical Application



Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input and Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, (V _{CC})			
DS7641	4.5	5.5	V
DS8641	4.75	5.25	V
Temperature Range, (T _A)			
DS7641	-55	+125	°C
DS8641	0	+70	°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Electrical Characteristics

The following apply for V_{MIN} ≤ V_{CC} ≤ V_{MAX}, T_{MIN} ≤ T_A ≤ T_{MAX} unless otherwise specified (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
DRIVER AND DISABLE INPUTS					
V _{IH} Logical "1" Input Voltage		2.0			V
V _{IL} Logical "0" Input Voltage				0.8	V
I _I Logical "1" Input Current	V _{IN} = 5.5V			1	mA
I _{IH} Logical "1" Input Current	V _{IN} = 2.4V			40	μA
I _{IL} Logical "0" Input Current	V _{IN} = 0.4V			-1.6	mA
V _{CL} Input Diode Clamp Voltage	I _{DIS} = -12 mA, I _{IN} = -12 mA, I _{BUS} = -12 mA, T _A = 25°C		-1	-1.5	V
DRIVER OUTPUT/RECEIVER INPUT					
V _{OLB} Low Level Bus Voltage	V _{DIS} = 0.8V, V _{IN} = 2V, I _{BUS} = 50 mA		0.4	0.7	V
I _{IHB} Maximum Bus Current	V _{IN} = 0.8V, V _{BUS} = 4V, V _{CC} = V _{MAX}		30	100	μA
I _{ILB} Maximum Bus Current	V _{IN} = 0.8V, V _{BUS} = 4V, V _{CC} = 0V		2	100	μA
V _{IH} High Level Receiver Threshold	V _{IND} = 0.8V, V _{OL} = 16 mA	DS7641 1.80 DS8641 1.70	1.50 1.50		V
V _{IL} Low Level Receiver Threshold	V _{IND} = 0.8V, V _{OH} = -400μA	DS7641 1.50 DS8641 1.50	1.50 1.30	1.20	V
RECEIVER OUTPUT					
V _{OH} Logical "1" Output Voltage	V _{IN} = 0.8V, V _{BUS} = 0.5V, I _{OH} = -400μA	2.4			V
V _{OL} Logical "0" Output Voltage	V _{IN} = 0.8V, V _{BUS} = 4V, I _{OL} = 16 mA		0.25	0.4	V
I _{OSS} Output Short Circuit Current	V _{DIS} = 0.8V, V _{IN} = 0.8V, V _{BUS} = 0.5V, V _{OSS} = 0V, V _{CC} = V _{MAX} , (Note 4)	-18		-55	mA
I _{CC} Supply Current	V _{DIS} = 0V, V _{IN} = 2V, (Per Package)		50	70	mA

Switching Characteristics T_A = 25°C, V_{CC} = 5V, unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd} Propagation Delays (Note 7)					
Disable to Bus "1"	(Note 5)		19	30	ns
Disable to Bus "0"			15	30	ns
Driver Input to Bus "1"			17	25	ns
Driver Input to Bus "0"			17	25	ns
Bus to Logical "1" Receiver Output	(Note 6)		20	30	ns
Bus to Logical "0" Receiver Output			18	30	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7641 and across the 0°C to +70°C range for the DS8641. All typical values are for T_A = 25°C and V_{CC} = 5V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: 91Ω from bus pin to V_{CC} and 200Ω from bus pin to ground. C_{LOAD} = 15 pF total. Measured from V_{IN} = 1.5V to V_{BUS} = 1.5V, V_{IN} = 0V to 3V pulse.

Note 6: Fan-out of 10 load, C_{LOAD} = 15 pF total. Measured from V_{IN} = 1.5V to V_{OUT} = 1.5V, V_{IN} = 0V to 3V pulse.

Note 7: The following apply for V_{CC} = 5V, T_A = 25°C unless otherwise specified.

DS8642 Quad Transceiver

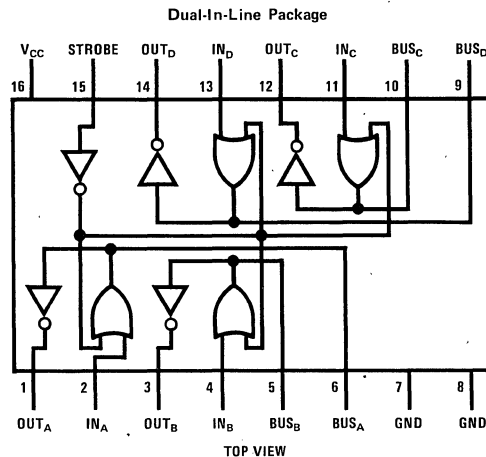
General Description

The DS8642 is a quad transceiver designed for bus organized data transmission systems terminated by 50Ω impedance. The bus can be terminated at one or both ends. It has four bus drivers with a common strobe gate and four bus receivers. Bus driver outputs can be "OR-tied" with up to 19 other drivers and with up to 20 bus receiver loads. The bus loading is $2k$ when $V_{CC} = 0V$.

Features

- 100 mA Drive Capability
- Four separate driver/receiver pairs
- Open collector driver output allows wire-OR connection
- 50Ω line termination
- Completely TTL compatible on driver and disable inputs, and receiver outputs

Logic and Connection Diagram



Order Number DS8642J
or DS8642N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}	4.75	5.25	V
Temperature, T_A	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
DISABLE/DRIVER INPUT						
V_{IH}	Logical "1" Input Voltage	$V_{CC} = \text{Min}$	2			V
V_{IL}	Logical "0" Input Voltage	$V_{CC} = \text{Min}$			0.8	V
I_{IL}	Logical "0" Input Current	$V_{CC} = \text{Max}, V_{IN} = 0.4V$		-0.9	-1.6	mA
I_{IH}	Logical "1" Input Current	$V_{CC} = \text{Max}$			40	μA
					1	mA
V_{CD}	Input Clamp Voltage	$I_{IN} = -12 \text{ mA}$		-0.8	-1.5	V
RECEIVER INPUT/BUS OUTPUT						
V_{IHB}	Logical "1" Input Voltage	$V_{CC} = \text{Max}$	3.1			V
V_{ILB}	Logical "0" Input Voltage	$V_{CC} = \text{Min}$			1.4	V
V_{CDB}	Input Clamp Diode	$I_{IN} = -50 \text{ mA}$		-1.0	-1.5	V
I_{IHB}	Logical "1" Input Current	$V_{CC} = \text{Max}, V_{INB} = V_{CC}$		180	450	μA
I_{ILB}	Logical "0" Input Current	$V_{CC} = \text{Max}, V_{IN} = 0.4V$			-40	μA
V_{OLB}	Logical "0" Output Voltage	$V_{CC} = \text{Min}, I_{OUT} = 100 \text{ mA}$		0.4	0.8	V
I_{OL}	Logical "0" Output Current	$V_{CC} = \text{Min}, V_{OL} = 0.8V$	100			mA
I_{OHB}	Power "OFF" Bus Current	$V_{CC} = 0V, V_{INB} = 5.25V$		1.7	2.65	mA
RECEIVER OUTPUT						
V_{OH}	Logical "1" Output Voltage	$V_{CC} = \text{Min}, I_{OUT} = -1 \text{ mA}$	2.4	3.2		V
I_{OH}	Logical "1" Output Current	$V_{CC} = \text{Min}, V_{OUT} = 5.5V$			100	μA
I_{OS}	Output Short Circuit Current	$V_{CC} = \text{Min}, V_{OUT} = 0V, (\text{Note 4})$	-10	-28	-55	mA
V_{OL}	Logical "0" Output Voltage	$V_{CC} = \text{Min}, I_{OUT} = 16 \text{ mA}$		0.3	0.45	V
I_{CC}	Supply Current	$V_{CC} = \text{Max}$		49	64	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS8642. All typicals are given for $V_{CC} = 5V$ and $T_A = 25^\circ C$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

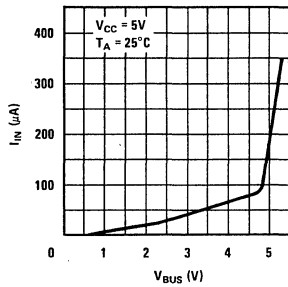
Note 4: Only one output at a time should be shorted.

Switching Characteristics $T_A = 25^\circ\text{C}$, nominal power supplies unless otherwise noted

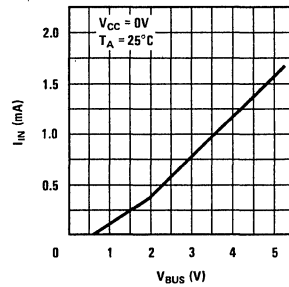
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{pd0}	Propagation Delay to a Logical "0" From Data Input to Receiver Output		34	50	ns
t_{pd1}	Propagation Delay to a Logical "1" From Data Input to Receiver Output		25	50	ns
t_{pd0}	Propagation Delay to a Logical "0" From Strobe Input to Receiver Output		38	55	ns
t_{pd1}	Propagation Delay to a Logical "1" From Strobe Input to Receiver Output		25	55	ns

Typical Performance Characteristics

Receiver ON Impedance



Receiver OFF Impedance



AC Test Circuit and Switching Time Waveforms

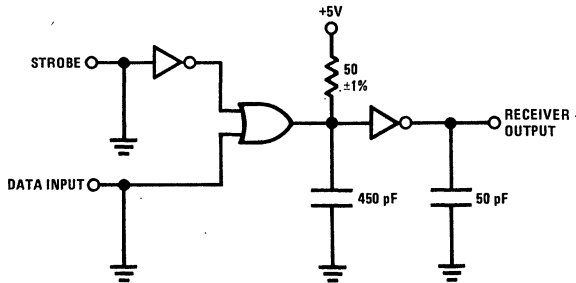
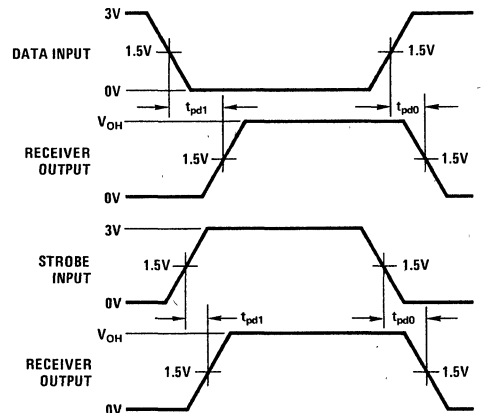


FIGURE 1.



$f = 5\text{ MHz}$
Pulse Width = 100 ns
 $t_r = t_f \approx 5\text{ ns}$

**DS7833/DS8833, DS7835/DS8835
Quad TRI-STATE® Bus Transceivers**
General Description

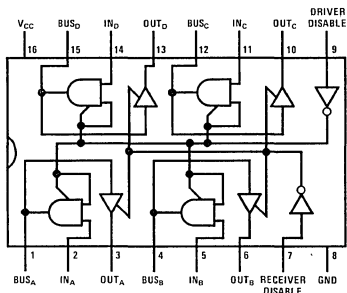
This family of TRI-STATE bus transceivers offer extreme versatility in bus organized data transmission systems. The data bus may be unterminated, or terminated dc or ac, at one or both ends. Drivers in the third (high impedance) state load the data bus with a negligible leakage current. The receiver input current is low allowing at least 100 driver/receiver pairs to utilize a single bus. The bus loading is unchanged when $V_{CC} = 0V$. The receiver incorporates hysteresis to provide greater noise immunity. All devices utilize a high current TRI-STATE output driver. The DS7833/DS8833 and DS7835/DS8835 employ TRI-STATE outputs on the receiver also.

The DS7833/DS8833 are non-inverting quad transceivers with a common inverter driver disable control and a common inverter receiver disable control.

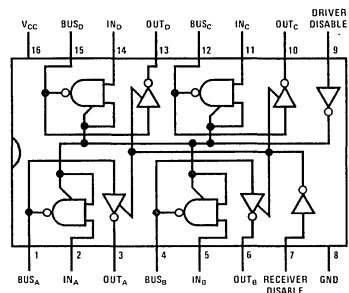
The DS7835/DS8835 are inverting quad transceivers with a common inverter driver disable control and a common inverter receiver disable control.

Features

- Receiver hysteresis 400 mV typ
- Receiver noise immunity 1.4V typ
- Bus terminal current for normal V_{CC} or $V_{CC} = 0V$ 80 μ A max
- Receivers
 - Sink 16 mA at 0.4V max
 - Source 2.0 mA (Mil) at 2.4V min
 - 5.2 mA (Com) at 2.4V min
- Drivers
 - Sink 50 mA at 0.5V max
 - 32 mA at 0.4V max
 - Source 10.4 mA (Com) at 2.4V min
 - 5.2 mA (Mil) at 2.4V min
- Drivers have TRI-STATE outputs
- DS7833/DS8833, DS7835/DS8835 receivers have TRI-STATE outputs
- Capable of driving 100 Ω dc-terminated buses
- Compatible with Series 54/74

2
Connection Diagrams
Dual-In-Line Package


**Order Number DS7833J, DS8833J
or DS8833N**
See NS Package J16A or N16A

Dual-In-Line Package


**Order Number DS7835J, DS8835J
or DS8835N**
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1) Operating Conditions

			MIN	MAX	UNITS
Supply Voltage	7.0V	Supply Voltage (V _{CC})			
Input Voltage	5.5V	DS7833, DS7835	4.5	5.5	V
Output Voltage	5.5V	DS8833, DS8835	4.75	5.25	V
Storage Temperature	-65°C to +150°C	Temperature (T _A)			
Maximum Power Dissipation* at 25°C		DS7833, DS7835	-55	+125	°C
Cavity Package	1509 mW	DS8833, DS8835	0	+70	°C
Molded Package	1476 mW				
Lead Temperature (Soldering, 10 seconds)	300°C				

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
DISABLE/DRIVER INPUT						
V _{IH} High Level Input Voltage	V _{CC} = Min	2.0			V	
V _{IL} Low Level Input Voltage	V _{CC} = Min	DS7833, DS8833, DS8835		0.8	V	
		DS7835		0.7		
I _{IH} High Level Input Current	V _{CC} = Max	V _{IN} = 2.4V		40	μA	
		V _{IN} = 5.5V		1.0	mA	
I _{IL} Low Level Input Current	V _{CC} = Max, V _{IN} = 0.4V		-1.0	-1.6	mA	
V _{CL} Input Clamp Diode	V _{CC} = 5.0V, I _{IN} = -12 mA, T _A = 25°C		-0.8	-1.5	V	
I _{IT} Driver Low Level Disabled Input Current	Driver Disable Input = 2.0V, V _{IN} = 0.4V			-40	μA	
RECEIVER INPUT/BUS OUTPUT						
V _{TH} High Level Threshold Voltage		DS7833, DS7835	1.4	1.75	2.1	V
		DS8833, DS8835	1.5	1.75	2.0	V
V _{TL} Low Level Threshold Voltage		DS7833, DS7835	0.8	1.35	1.6	V
		DS8833, DS8835	0.8	1.35	1.5	V
I _B Bus Current; Output Disabled or High	V _{BUS} = 4.0V	V _{CC} = Max		25	80	μA
		V _{CC} = 0V		5.0	80	μA
		V _{CC} = Max, V _{BUS} = 0.4V		-2.0	-40	μA
V _{OH} Logic "1" Output Voltage	V _{CC} = Min	I _{OUT} = -5.2 mA	DS7833, DS7835	2.4	2.75	V
		I _{OUT} = -10.4 mA	DS8833, DS8835	2.4	2.75	V
V _{OL} Logic "0" Output Voltage	V _{CC} = Min	I _{OUT} = 50 mA		0.28	0.5	V
		I _{OUT} = 32 mA			0.4	V
I _{OS} Output Short Circuit Current	V _{CC} = Max, (Note 4)		-40	-62	-120	mA
RECEIVER OUTPUT						
V _{OH} Logic "1" Output Voltage	V _{CC} = Min	I _{OUT} = -2.0 mA	DS7833, DS7835	2.4	3.0	V
		I _{OUT} = -5.2 mA	DS8833, DS8835	2.4	2.9	V
V _{OL} Logic "0" Output Voltage	V _{CC} = Min, I _{OUT} = 16 mA			0.22	0.4	V
I _{OT} Output Disabled Current	V _{CC} = Max, Disable Inputs = 2.0V	V _{OUT} = 2.4V			40	μA
		V _{OUT} = 0.4V			-40	μA
I _{OS} Output Short Circuit Current	V _{CC} = Max, (Note 4)	DS7833, DS7835	-28	-40	-70	mA
		DS8833, DS8835	-30		-70	mA
I _{CC} Supply Current	V _{CC} = Max	DS7833/DS8833		84	116	mA
		DS7835/DS8835		75	95	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7833, DS7835 and across the 0°C to +70°C range for the DS8833, DS8835. All typicals are given for V_{CC} = 5.0V and T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Switching Characteristics $V_{CC} = 5.0V, T_A = 25^\circ C$

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
t_{pd0} Propagation Delay to a Logic "0" From Input to Bus	(Figure 1)	DS7833/DS8833		14	30	ns
		DS7835/DS8835		10	20	ns
t_{pd1} Propagation Delay to a Logic "1" From Input to Bus	(Figure 1)	DS7833/DS8833		14	30	ns
		DS7835/DS8835		11	30	ns
t_{pd0} Propagation Delay to a Logic "0" From Bus to Output	(Figure 2)	DS7833/DS8833		24	45	ns
		DS7835/DS8835		16	35	ns
t_{pd1} Propagation Delay to a Logic "1" From Bus to Output	(Figure 2)	DS7833/DS8833		12	30	ns
		DS7835/DS8835		18	30	ns
t_{PHZ} Delay From Disable Input to High Impedance State (From Logic "1" Level)	$C_L = 5.0 \text{ pF}$, (Figures 1 and 2)	Driver		8.0	20	ns
		Receiver		6.0	15	ns
t_{PLZ} Delay From Disable Input to High Impedance State (From Logic "0" Level)	$C_L = 5.0 \text{ pF}$, (Figures 1 and 2)	Driver		20	35	ns
		Receiver		13	25	ns
t_{PZH} Delay From Disable Input to Logic "1" Level (From High Impedance State)	$C_L = 50 \text{ pF}$, (Figures 1 and 2)	Driver		24	40	ns
		Receiver		16	35	ns
t_{PZL} Delay From Disable Input to Logic "0" Level (From High Impedance State)	$C_L = 50 \text{ pF}$, (Figures 1 and 2)	Driver		19	35	ns
		Receiver DS7833/DS8833		15	30	ns
		Receiver DS7835/DS8835		33	50	ns

AC Test Circuits

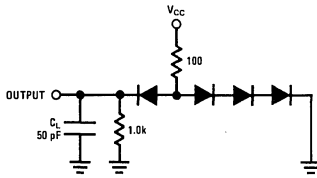


FIGURE 1. Driver Output Load

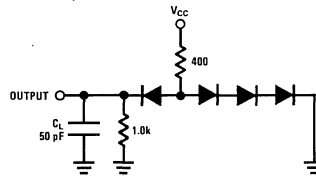
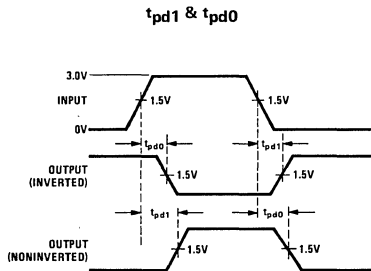
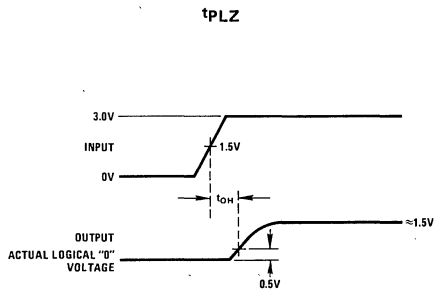


FIGURE 2. Receiver Output Load

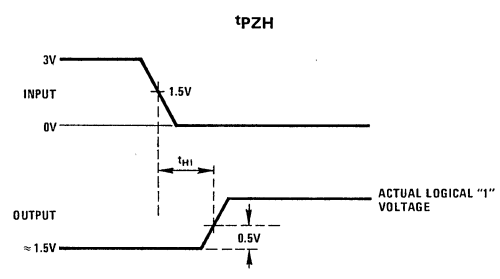
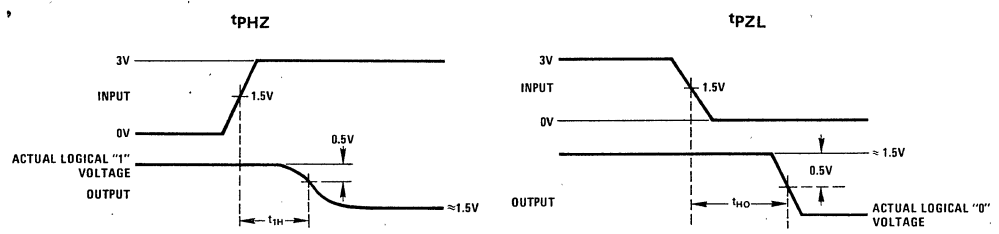
Switching Time Waveforms



$f = 1 \text{ MHz}$
 $t_r = t_f \leq 10 \text{ ns}$ (10% to 90%)
 DUTY CYCLE = 50%



Switching Time Waveforms (Continued)



**DS7834/DS8834, DS7839/DS8839
Quad TRI-STATE® Bus Transceivers**
General Description

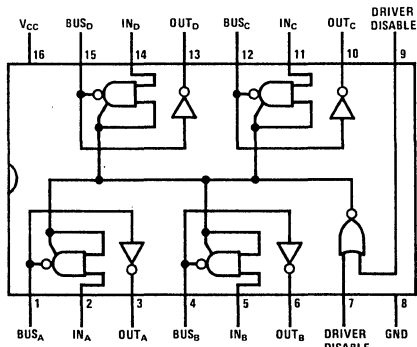
This family of TRI-STATE bus transceivers offers extreme versatility in bus organized data transmission systems. The data bus may be unterminated, or terminated dc or ac, at one or both ends. Drivers in the third (high impedance) state load the data bus with a negligible leakage current. The receiver input current is low, allowing at least 100 driver/receiver pairs to utilize a single bus. The bus loading is unchanged when $V_{CC} = 0V$. The receiver incorporates hysteresis to provide greater noise immunity. Both devices utilize a high current TRI-STATE output driver. The DS7834/DS8834 and DS7839/DS8839 employ TTL outputs on the receiver.

The DS7839/DS8839 are non-inverting quad transceivers with two common inverter driver disable controls.

The DS7834/DS8834 are inverting quad transceivers with two common inverter driver disable controls.

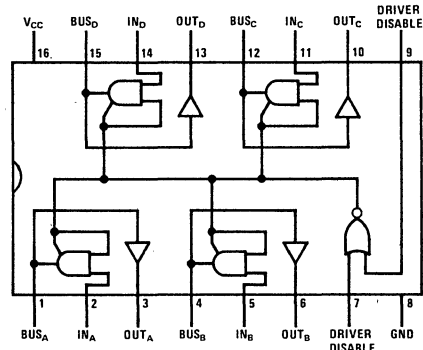
Features

- Receiver hysteresis 400 mV typ
- Receiver noise immunity 1.4V typ
- Bus terminal current for normal V_{CC} or $V_{CC} = 0V$ 80 μ A max
- Receivers
 - Sink 16 mA at 0.4V max
 - Source 2.0 mA (Mil) at 2.4V min
 - 5.2 mA (Com) at 2.4V min
- Drivers
 - Sink 50 mA at 0.5V max
 - 32 mA at 0.4V max
 - Source 10.4 mA (Com) at 2.4V min
 - 5.2 mA (Mil) at 2.4V min
- Drivers have TRI-STATE outputs
- Receivers have TRI-STATE outputs
- Capable of driving 100 Ω dc-terminated buses
- Compatible with Series 54/74

Connection Diagrams
Dual-In-Line Package


TOP VIEW

**Order Number DS7834J, DS8834J
or DS8834N
See NS Package J16A or N16A**

Dual-In-Line Package


TOP VIEW

**Order Number DS7839J, DS8839J
or DS8839N
See NS Package J16A or N16A**

Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 Seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7834, DS7839	4.5	5.5	V
DS8834, DS8839	4.75	5.25	V
Temperature (T _A)			
DS7834, DS7839	-55	+125	°C
DS8834, DS8839	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
DISABLE/DRIVER INPUT						
V _{IH} High Level Input Voltage	V _{CC} = Min		2.0			V
V _{IL} Low Level Input Voltage	V _{CC} = Min				0.8	V
I _{IH} High Level Input Current	V _{CC} = Max	V _{IN} = 2.4V			40	μA
		V _{IN} = 5.5V			1.0	mA
I _{IL} Low Level Input Current	V _{CC} = Max, V _{IN} = 0.4V			-1.0	-1.6	mA
I _{IND} Driver Disabled Input Low Current	Driver Disable Input = 2.0V, V _{IN} = 0.4V				-40	μA
V _{CL} Input Clamp Diode	V _{CC} = 5.0V, I _{IN} = -12 mA, T _A = 25°C			-0.8	-1.5	V
RECEIVER INPUT/BUS OUTPUT						
V _{TH} High Level Threshold Voltage	V _{CC} = Max	DS7834, DS7839	1.4	1.75	2.1	V
		DS8834, DS8839	1.5	1.75	2.0	V
V _{TL} Low Level Threshold Voltage	V _{CC} = Min	DS7834, DS7839	0.8	1.35	1.6	V
		DS8834, DS8839	0.8	1.35	1.5	V
I _{BH} Bus Current, Output Disabled or High	V _{BUS} = 4.0V	V _{CC} = Max, Disable Input = 2.0V		25	80	μA
		V _{CC} = 0V		5.0	80	μA
		V _{CC} = Max, V _{BUS} = 0.4V, Disable Input = 2.0V				-40
V _{OH} Logic "1" Output Voltage	V _{CC} = Min	I _{OUT} = -5.2 mA	DS7834, DS7839	2.4	2.75	V
		I _{OUT} = -10.4 mA	DS7834, DS8839	2.4	2.75	V
V _{OL} Logic "0" Output Voltage	V _{CC} = Min	I _{OUT} = 50 mA		0.28	0.5	V
		I _{OUT} = 32 mA			0.4	V
I _{OS} Output Short Circuit Current	V _{CC} = Max, (Note 4)		-40	-62	-120	mA
RECEIVER OUTPUT						
V _{OH} Logic "1" Output Voltage	V _{CC} = Min	I _{OUT} = -2.0 mA	DS7834, DS7839	2.4	3.0	V
		I _{OUT} = -5.2 mA	DS8834, DS8839	2.4	2.9	V
V _{OL} Logic "0" Output Voltage	V _{CC} = Min, I _{OUT} = 16 mA			0.22	0.4	V
I _{OS} Output Short Circuit Current	V _{CC} = Max, (Note 4)	DS7834, DS7839	-28	-40	-70	mA
		DS8834, DS8839	-30		-70	mA
I _{CC} Supply Current	V _{CC} = Max			75	95	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7834, DS7839 and across the 0°C to +70°C range for the DS8834, DS8839. All typicals are given for V_{CC} = 5.0V and T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Switching Characteristics $V_{CC} = 5.0V, T_A = 25^\circ C$

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
t_{pd0}	Propagation Delay to a Logic "0" from Input to Bus	(Figure 1) DS7839/DS8839 DS7834/DS8834		14 10	30 20	ns
t_{pd1}	Propagation Delay to a Logic "1" from Input to Bus	(Figure 1) DS7839/DS8839 DS7834/DS8834		14 11	30 30	ns
t_{pd0}	Propagation Delay to a Logic "0" from Bus to Output	(Figure 2) DS7839/DS8839 DS7834/DS8834		24 16	45 35	ns
t_{pd1}	Propagation Delay to a Logic "1" from Bus to Output	(Figure 2) DS7839/DS8839 DS7834/DS8834		12 18	30 30	ns
t_{PHZ}	Delay from Disable Input to High Impedance State (from Logic "1" Level)	$C_L = 5.0 \text{ pF}$, (Figures 1 and 2) Driver Only		8	20	ns
t_{PLZ}	Delay from Disable Input to High Impedance State (from Logic "0" Level)	$C_L = 5.0 \text{ pF}$, (Figures 1 and 2) Driver Only		20	35	ns
t_{PZH}	Delay from Disable Input to Logic "1" Level (from High Impedance State)	$C_L = 50 \text{ pF}$, (Figures 1 and 2) Driver Only		24	40	ns
t_{PZL}	Delay from Disable Input to Logic "0" Level (from High Impedance State)	$C_L = 50 \text{ pF}$, (Figures 1 and 2) Driver Only		19	35	ns

AC Test Circuit

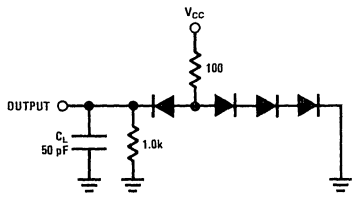


FIGURE 1. Driver Output Load

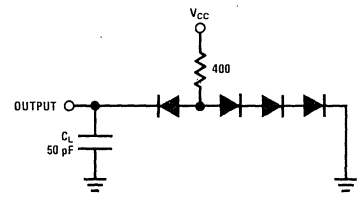
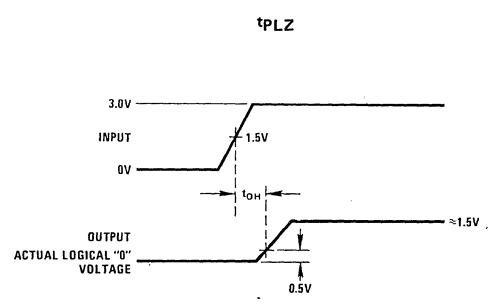
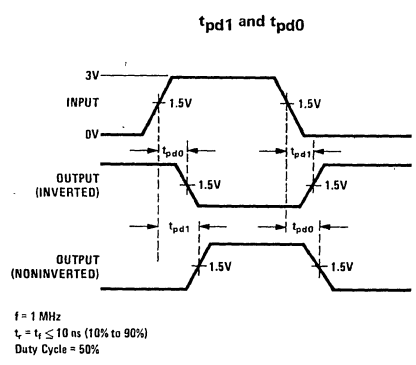
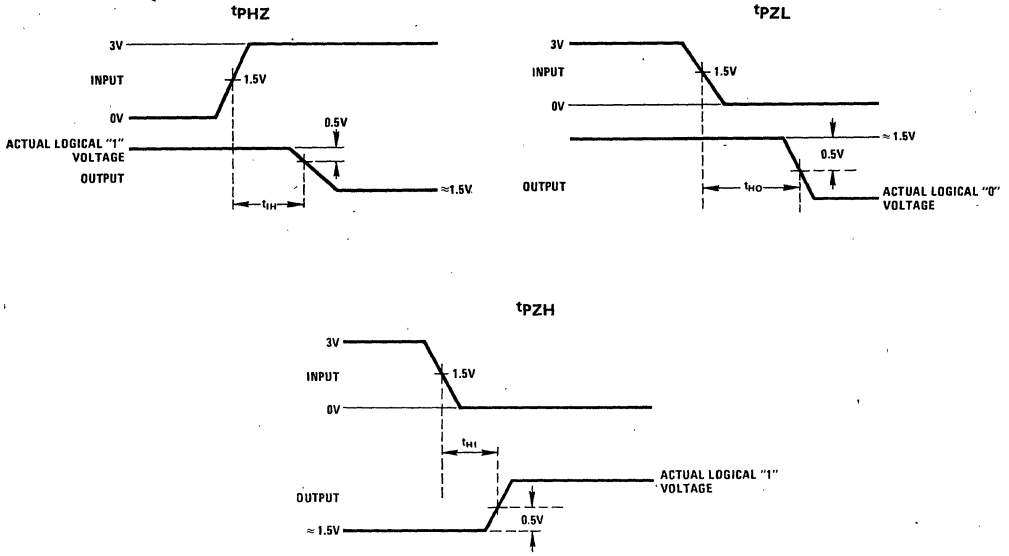


FIGURE 2. Receiver Output Load

Switching Time Waveforms



Switching Time Waveforms (Continued)



Truth Table

DISABLE INPUT	DRIVER INPUT (IN _x)	RECEIVER INPUT/ BUS OUTPUT (BUS _x)	RECEIVER OUTPUT (OUT _x)	MODE OF OPERATION
DS7834/DS8834				
1	X		BUS	Receive bus signal
0	1	0	1	Drive bus
0	0	1	0	Drive bus
DS7839/DS8839				
1	X		BUS	Receive bus signal
0	1	1	1	Drive bus
0	0	0	0	Drive bus

X = Don't care

DS7836/DS8836 Quad NOR Unified Bus Receiver

General Description

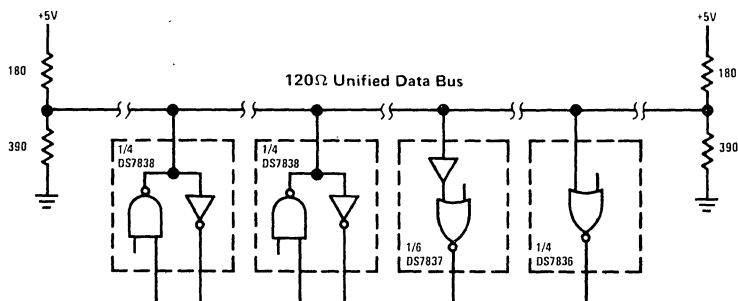
The DS7836/DS8836 are quad 2-input receivers designed for use in bus organized data transmission systems interconnected by terminated 120Ω impedance lines. The external termination is intended to be 180Ω resistor from the bus to the +5V logic supply together with a 390Ω resistor from the bus to ground. The design employs a built-in input hysteresis providing substantial noise immunity. Low input current allows up to 27 driver/receiver pairs to utilize a common bus. Performance is optimized for systems with bus rise and fall times $\leq 1.0 \mu\text{s}/\text{V}$.

Features

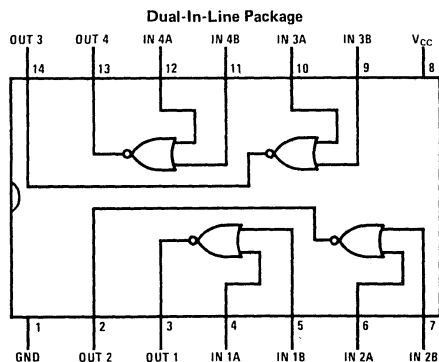
- Low input current with normal V_{CC} or $V_{CC} = 0\text{V}$ ($15 \mu\text{A}$ typ)
- Built-in input hysteresis (1V typ)
- High noise immunity (2V typ)
- Temperature-insensitive input thresholds track bus logic levels
- TTL compatible output
- Matched, optimized noise immunity for "1" and "0" levels
- High speed (18 ns typ)

2

Typical Application



Connection Diagram



TOP VIEW
 Order Number DS7836J Order Number DS8836N
 or DS8836J See NS Package N14A
 See NS Package J14A

Absolute Maximum Ratings

Supply Voltage	7.0V
Current Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})			
DS7836	4.5	5.5	V
DS8836	4.75	5.25	V
Temperature (T_A)			
DS7836	-55	+125	°C
DS8836	0	+70	°C

*Derate cavity package 8.7 mW/°C above 25°C; derate molded package 9.7 mW/°C above 25°C.

Electrical Characteristics

The following apply for $V_{MIN} \leq V_{CC} \leq V_{MAX}$, $T_{MIN} \leq T_A \leq T_{MAX}$, unless otherwise specified (Notes 2 and 3)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
V_{TH}	High Level Input Threshold	$V_{CC} = \text{Max}$	DS7836	1.65	2.25	2.65	V
			DS8836	1.80	2.25	2.50	V
V_{IL}	Low Level Input Threshold	$V_{CC} = \text{Min}$	DS7836	0.97	1.30	1.63	V
			DS8836	1.05	1.30	1.55	V
I_{IN}	Maximum Input Current	$V_{IN} = 4V$	$V_{CC} = \text{Max}$		15	50	μA
			$V_{CC} = 0V$		1	50	μA
V_{OH}	Logical "1" Output Voltage	$V_{IN} = 0.5V$, $I_{OUT} = -400\mu\text{A}$		2.4			V
V_{OL}	Logical "0" Output Voltage	$V_{IN} = 4V$, $I_{OUT} = 16\text{ mA}$			0.25	0.4	V
I_{SC}	Output Short Circuit Current	$V_{IN} = 0.5V$, $V_{OUT} = 0V$, $V_{CC} = \text{Max}$, (Note 4)		-18		-55	mA
I_{CC}	Power Supply Current	$V_{IN} = 4V$, (Per Package)			25	40	mA
V_{CL}	Input Clamp Diode Voltage	$I_{IN} = -12\text{ mA}$, $T_A = 25^\circ\text{C}$			-1	-1.5	V

Switching Characteristics

$V_{CC} = 5V$, $T_A = 25^\circ\text{C}$ unless otherwise specified.

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
t_{pd}	Propagation Delays	(Notes 4 and 5)	Input to Logical "1" Output		20	30	ns
			Input to Logical "0" Output		18	30	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7836 and across the 0°C to +70°C range for the DS8836. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Fan-out of 10 load, $C_{LOAD} = 15\text{ pF}$ total, measured from $V_{IN} = 1.3V$ to $V_{OUT} = 1.5V$, $V_{IN} = 0V$ to 3V pulse.

Note 5: Fan-out of 10 load, $C_{LOAD} = 15\text{ pF}$ total, measured from $V_{IN} = 2.3V$ to $V_{OUT} = 1.5V$, $V_{IN} = 0V$ to 3V pulse.

DS7837/DS8837 Hex Unified Bus Receiver

General Description

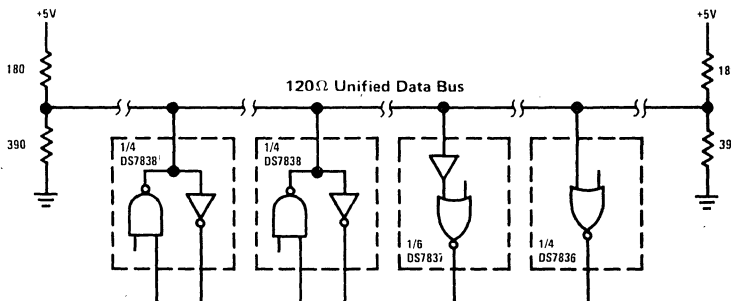
The DS7837/DS8837 are high speed receivers designed for use in bus organized data transmission systems interconnected by terminated 120Ω impedance lines. The external termination is intended to be 180Ω resistor from the bus to the +5V logic supply together with a 390Ω resistor from the bus to ground. The receiver design employs a built-in input hysteresis providing substantial noise immunity. Low input current allows up to 27 driver/receiver pairs to utilize a common bus. Disable inputs provide time discrimination. Disable inputs and receiver outputs are TTL compatible. Performance is optimized for systems with bus rise and fall times $\leq 1.0\mu\text{s}/\text{V}$.

Features

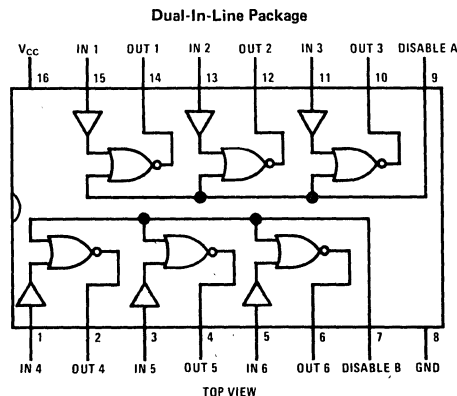
- Low receiver input current for normal V_{CC} or $V_{CC} = 0\text{V}$ ($15\mu\text{A typ}$)
- Six separate receivers per package
- Built-in receiver input hysteresis (1V typ)
- High receiver noise immunity (2V typ)
- Temperature insensitive receiver input thresholds track bus logic levels
- TTL compatible disable and output
- Molded or cavity dual-in-line or flat package
- High speed

2

Typical Application



Connection Diagram



Order Number DS7837J
or DS8837J
See NS Package J16A

Order Number DS8837N
See NS Package N16A

Absolute Maximum Ratings

Supply Voltage	7V
Input Voltage	5.5V
Operating Temperature Range	
DS7837	-55°C to +125°C
DS8837	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7837	4.5	5.5	V
DS8837	4.75	5.25	V
Temperature (T _A)			
DS7837	-55	+125	°C
DS8837	0	+70	°C

Electrical Characteristics

The following apply for V_{MIN} ≤ V_{CC} ≤ V_{MAX}, T_{MIN} ≤ T_A ≤ T_{MAX}, unless otherwise specified (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{TH} High Level Receiver Threshold	V _{CC} = Max	DS7837	1.65	2.25	2.65	V
		DS8837	1.80	2.25	2.50	V
V _{TL} Low Level Receiver Threshold	V _{CC} = Min	DS7837	0.97	1.30	1.63	V
		DS8837	1.05	1.30	1.55	V
I _{IH} Maximum Receiver Input Current	V _{IN} = 4V	V _{CC} = V _{MAX}		15.0	50.0	μA
		V _{CC} = 0V		1.0	50.0	μA
I _{IL} Logical "0" Receiver Input Current	V _{IN} = 0.4V, V _{CC} = V _{MAX}		1.0	50.0	μA	
V _{IH} Logical "1" Input Voltage	Disable	2.0			V	
V _{IL} Logical "0" Input Voltage	Disable			0.8	V	
I _{IH} Logical "1" Input Current	Disable Input	V _{IND} = 2.4V		80.0	μA	
		V _{IND} = 5.5V		2.0	mA	
I _{IL} Logical "0" Input Current	V _{IN} = 4V, V _{IND} = 0.4V, Disable Input			-3.2	mA	
V _{OH} Logical "1" Output Voltage	V _{IN} = 0.5V, V _{IND} = 0.8V, I _{OH} = -400μA	2.4			V	
V _{OL} Logical "0" Output Voltage	V _{IN} = 4V, V _{IND} = 0.8V, I _{OL} = 16 mA		0.25	0.4	V	
I _{OS} Output Short Circuit Current	V _{IN} = 0.5V, V _{IND} = 0V, V _{OS} = 0V, V _{CC} = V _{MAX} , (Note 4)	-18.0		-55.0	mA	
I _{CC} Power Supply Current	V _{IN} = 4V, V _{IND} = 0V, (Per Package)		45.0	60.0	mA	
V _{CL} Input Clamp Diode	V _{IN} = -12 mA, V _{IND} = -12 mA, T _A = 25°C	-1.0		-1.5	V	

Switching Characteristics T_A = 25°C, nominal power supplies unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t _{pd} Propagation Delays	V _{IND} = 0V, Receiver	Input to Logical "1" Output, (Note 5)		20	30	ns
		Input to Logical "0" Output, (Note 6)		18	30	ns
	Input = 0V, Disable, (Note 7)	Input to Logical "1" Output		9	15	ns
		Input to Logical "0" Output		4	10	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7837 and across the 0°C to +70°C range for the DS8837. All typical values are for T_A = 25°C and V_{CC} = 5V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: Fan-out of 10 load, C_{LOAD} = 15 pF total. Measured from V_{IN} = 1.3V to V_{OUT} = 1.5V, V_{IN} = 0V to 3V pulse.

Note 6: Fan-out of 10 load, C_{LOAD} = 15 pF total. Measured from V_{IN} = 2.3V to V_{OUT} = 1.5V, V_{IN} = 0V to 3V pulse.

Note 7: Fan-out of 10 load, C_{LOAD} = 15 pF total. Measured from V_{IN} = 1.5V to V_{OUT} = 1.5V, V_{IN} = 0V to 3V pulse.

DS7838/DS8838 Quad Unified Bus Transceiver

General Description

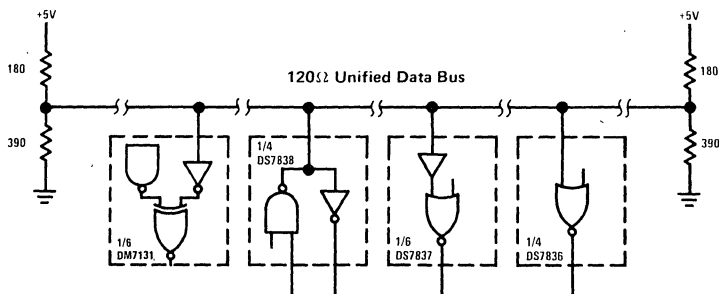
The DS7838/DS8838 are quad high speed drivers/receivers designed for use in bus organized data transmission systems interconnected by terminated 120Ω impedance lines. The external termination is intended to be a 180Ω resistor from the bus to the +5V logic supply together with a 390Ω resistor from the bus to ground. The bus can be terminated at one or both ends. Low bus pin current allows up to 27 driver/receiver pairs to utilize a common bus. The bus loading is unchanged when $V_{CC} = 0V$. The receivers incorporate hysteresis to greatly enhance bus noise immunity. One two-input NOR gate is included to disable all drivers in a package simultaneously. Receiver performance is optimized for systems with bus rise and fall times $\leq 1.0\mu s/V$.

Features

- 4 totally separate driver/receiver pairs per package
- 1V typical receiver input hysteresis
- Receiver hysteresis independent of receiver output load
- Guaranteed minimum bus noise immunity of 1.3V, 2V typ.
- Temperature-insensitive receiver thresholds track bus logic levels
- $20\mu A$ typical bus terminal current with normal V_{CC} or with $V_{CC} = 0V$
- Open collector driver output allows wire-OR connection
- High speed
- Series 74 TTL compatible driver and disable inputs and receiver outputs

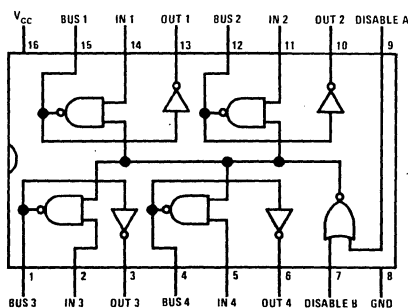
2

Typical Application



Connection Diagram

Dual-In-Line Package



Order Number DS7838J
or DS8838J
See NS Package J16A

Order Number DS8838N
See NS Package N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input and Output Voltage	5.5V
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW

Operating Temperature Range	
DS7838	-55°C to +125°C
DS8838	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Lead Temperature, (Soldering, 10 sec)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Electrical Characteristics

DS7838/DS8838: The following apply for $V_{MIN} \leq V_{CC} \leq V_{MAX}$, $T_{MIN} \leq T_A \leq T_{MAX}$ unless otherwise specified (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS		
DRIVER AND DISABLE INPUTS							
V_{IH}	Logical "1" Input Voltage	2.0			V		
V_{IL}	Logical "0" Input Voltage			0.8	V		
I_I	Logical "1" Input Current	$V_{IN} = 5.5V$		1	mA		
I_{IH}	Logical "1" Input Current	$V_{IN} = 2.4V$		40	μA		
I_{IL}	Logical "0" Input Current	$V_{IN} = 0.4V$		-1.6	mA		
V_{CL}	Input Diode Clamp Voltage	$I_{DIS} = -12\text{ mA}$, $I_{IN} = -12\text{ mA}$, $I_{BUS} = -12\text{ mA}$, $T_A = 25^\circ\text{C}$	-1	-1.5	V		
DRIVER OUTPUT/RECEIVER INPUT							
V_{OLB}	Low Level Bus Voltage	$V_{DIS} = 0.8V$, $V_{IN} = 2V$, $I_{BUS} = 50\text{ mA}$		0.4	0.7	V	
I_{IHB}	Maximum Bus Current	$V_{IN} = 0.8V$, $V_{BUS} = 4V$, $V_{CC} = V_{MAX}$		20	100	μA	
I_{ILB}	Maximum Bus Current	$V_{IN} = 0.8V$, $V_{BUS} = 4V$, $V_{CC} = 0V$		2	100	μA	
V_{IH}	High Level Receiver Threshold	$V_{IND} = 0.8V$, $V_{OL} = 16\text{ mA}$, $V_{CC} = \text{Max}$	DS7838	1.65	2.25	2.65	V
			DS8838	1.80	2.25	2.50	V
V_{IL}	Low Level Receiver Threshold	$V_{IND} = 0.8V$, $V_{OH} = -400\mu\text{A}$, $V_{CC} = \text{Min}$	DS7838	0.97	1.30	1.63	V
			DS8838	1.05	1.30	1.55	V
RECEIVER OUTPUT							
V_{OH}	Logical "1" Output Voltage	$V_{IN} = 0.8V$, $V_{BUS} = 0.5V$, $I_{OH} = -400\mu\text{A}$	2.4			V	
V_{OL}	Logical "0" Output Voltage	$V_{IN} = 0.8V$, $V_{BUS} = 4V$, $I_{OL} = 16\text{ mA}$		0.25	0.4	V	
I_{OS}	Output Short Circuit Current	$V_{DIS} = 0.8V$, $V_{IN} = 0.8V$, $V_{BUS} = 0.5V$, $V_{OS} = 0V$, $V_{CC} = V_{MAX}$, (Note 4)	-18		-55	mA	
I_{CC}	Supply Current	$V_{DIS} = 0V$, $V_{IN} = 2V$, (Per Package)		50	70	mA	
t_{pd}	Propagation Delays (Note 8)	Disable to Bus "1"	(Note 5)		19	30	ns
		Disable to Bus "0"	(Note 5)		15	23	ns
		Driver Input to Bus "1"	(Note 5)		17	25	ns
		Driver Input to Bus "0"	(Note 5)		9	15	ns
		Bus to Logical "1" Receiver Output	(Note 6)		20	30	ns
		Bus to Logical "0" Receiver Output	(Note 7)		18	30	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7838 and across the 0°C to +70°C range for the DS8838. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: 91Ω from bus pin to V_{CC} and 200Ω from bus pin to ground, $C_{LOAD} = 15\text{ pF}$ total. Measured from $V_{IN} = 1.5V$ to $V_{BUS} = 1.5V$, $V_{IN} = 0V$ to 3.0V pulse.

Note 6: Fan-out of 10 load, $C_{LOAD} = 15\text{ pF}$ total. Measured from $V_{IN} = 1.3V$ to $V_{OUT} = 1.5V$, $V_{IN} = 0V$ to 3.0V pulse.

Note 7: Fan-out of 10 load, $C_{LOAD} = 15\text{ pF}$ total. Measured from $V_{IN} = 2.3V$ to $V_{OUT} = 1.5V$, $V_{IN} = 0V$ to 3.0V pulse.

Note 8: These apply for $V_{CC} = 5V$, $T_A = 25^\circ\text{C}$ unless otherwise specified.

DS8T26A, DS8T26AM, DS8T28, DS8T28M

4-Bit Bidirectional Bus Transceivers

General Description

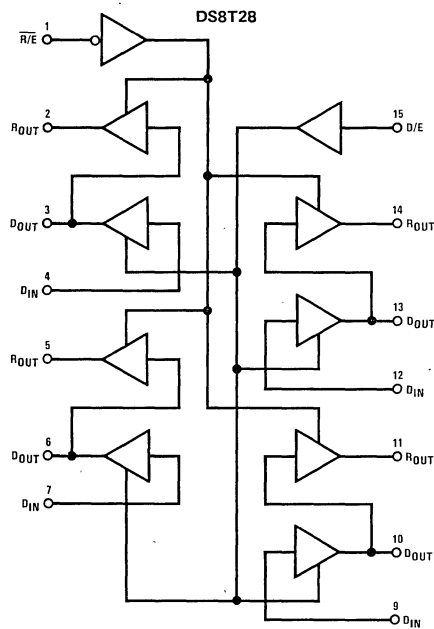
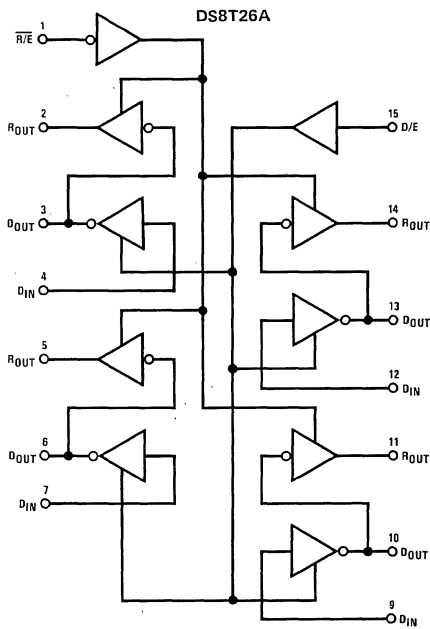
The DS8T26A, DS8T28 consist of 4 pairs of TRI-STATE[®] logic elements configured as quad bus drivers/receivers along with separate buffered receiver enable and driver enable lines. This single IC quad transceiver design distinguishes the DS8T26A, DS8T28 from conventional multi-IC implementations. In addition, the DS8T26A, DS8T28's ultra high speed while driving heavy bus capacitance (300 pF) makes these devices particularly suitable for memory systems and bidirectional data buses.

Both the driver and receiver gates have TRI-STATE outputs and low current PNP inputs. PNP inputs reduce input loading to 200 μ A maximum.

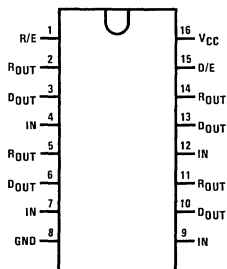
Features

- Inverting outputs in the DS8T26A
- Non-inverting outputs in the DS8T28
- TRI-STATE outputs
- Low current PNP inputs
- Fast switching times (20 ns)
- Advanced Schottky processing
- Driver glitch free power up/down
- Non-overlapping TRI-STATE

Logic and Connection Diagrams



Dual-In-Line Package



TOP VIEW

Order Number DS8T26AJ, DS8T26AMJ, DS8T28J,
DS8T28MJ, DS8T26AN or DS8T28N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

All Output and Supply Voltages	-0.5V to +7V
All Input Voltages	-1V to +5.5V
Output Currents	±150 mA
Storage Temperature	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Recommended Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS8T26A, DS8T28	4.75	5.25	V
DS8T26AM, DS8T28M	4.5	5.5	V
Temperature (T _A)			
DS8T26A, DS8T28	0	70	°C
DS8T26AM, DS8T28M	-55	+125	°C

Electrical Characteristics (Notes 2, 3 and 4)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
DRIVER					
I _{IL}	Low Level Input Current	V _{IN} = 0.4V			-200 μA
I _{IL}	Low Level Input Current (Disabled)	V _{IN} = 0.4V			-25 μA
I _{IH}	High Level Input Current (D _{IN} , D _E)	V _{IN} = V _{CC} Max			25 μA
V _{OL}	Low Level Output Voltage, (Pins 3, 6, 10, 13)	I _{OUT} = 48 mA			0.5 V
V _{OH}	High Level Output Voltage, (Pins 3, 6, 10, 13)	I _{OUT} = -10 mA	2.4		V
I _{OS}	Short-Circuit Output Current, (Pins 3, 6, 10, 13)	V _{OUT} = 0V, V _{CC} = V _{CC} Max	-50		-150 mA
RECEIVER					
I _{IL}	Low Level Input Current	V _{IN} = 0.4V			-200 μA
I _{IH}	High Level Input Current (R _E)	V _{IN} = V _{CC} Max			25 μA
V _{OL}	Low Level Output Voltage	I _{OUT} = 20 mA			0.5 V
V _{OH}	High Level Output Voltage, (Pins 2, 5, 11, 14)	I _{OUT} = -100 μA	3.5		V
		I _{OUT} = -2 mA	2.4		V
I _{OS}	Short-Circuit Output Current, (Pins 2, 5, 11, 14)	V _{OUT} = 0V, V _{CC} = V _{CC} Max	-30		-75 mA
BOTH DRIVER AND RECEIVER					
V _{TL}	Low Level Input Threshold Voltage	V _{CC} = Min, V _{IN} = 0.8V, I _{OL} = Max	0.85		V
V _{TH}	High Level Input Threshold Voltage	V _{CC} = Max, V _{IN} = 0.8V, I _{OH} = Max		2	V
I _{OZ}	Low Level Output OFF Leakage Current	V _{OUT} = 0.5V			-100 μA
I _{OZ}	High Level Output OFF Leakage Current	V _{OUT} = 2.4V			100 μA
V _I	Input Clamp Voltage	I _{IN} = -12 mA			-1.0 V
I _{CC}	Power Supply Current	DS8T26A			87 mA
		DST28	V _{CC} = V _{CC} Max		110 mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the -55°C to +125°C temperature range for the DS8T26AM, DS8T28M and across the 0°C to +70°C range for the DS8T26A, DS8T28. All typicals are given for V_{CC} = 5V and T_A = 25°C.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

Switching Characteristics

PARAMETER	CONDITIONS	DS8T26A MAX	DS8T28 MAX	UNITS
Propagation Delay				
t_{ON}	D_{OUT} to R_{OUT} , (Figure 1)	14	17	ns
t_{OFF}	D_{OUT} to R_{OUT} , (Figure 1)			
t_{ON}	D_{IN} to D_{OUT} , (Figure 2)	14	17	ns
t_{OFF}	D_{IN} to D_{OUT} , (Figure 2)			
Data Enable to Data Output				
t_{PZL}	High Z to O, (Figure 3)	25	28	ns
t_{PLZ}	O to High Z, (Figure 3)			
Receiver Enable to Receiver Output				
t_{PZL}	High Z to O, (Figure 4)	20	23	ns
t_{PLZ}	O to High Z, (Figure 4)			

AC Test Circuits and Switching Time Waveforms

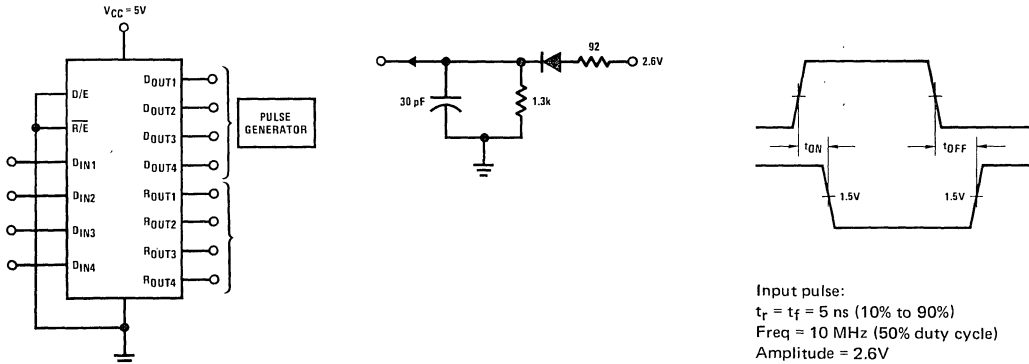


FIGURE 1. Propagation Delay (D_{OUT} to R_{OUT})

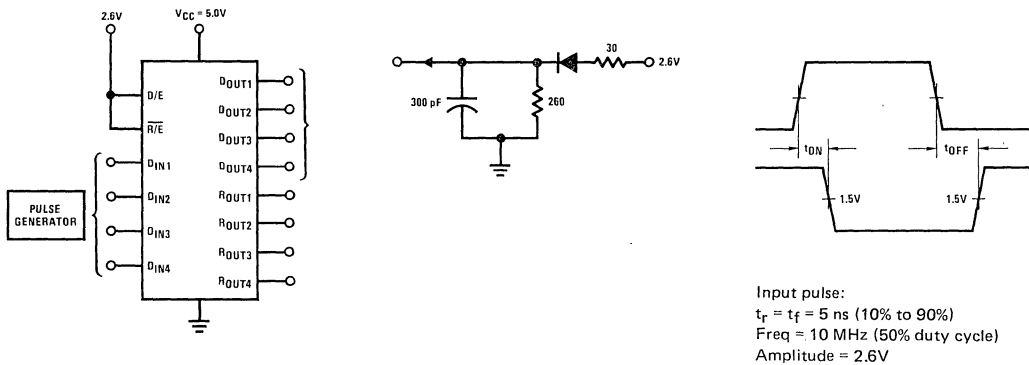


FIGURE 2. Propagation Delay (D_{IN} to D_{OUT})

AC Test Circuits and Switching Time Waveforms (Continued)

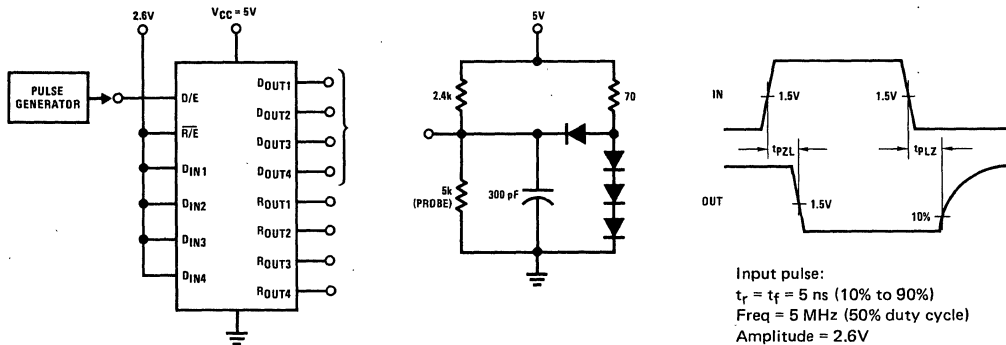


FIGURE 3. Propagation Delay (Data Enable to Data Output)

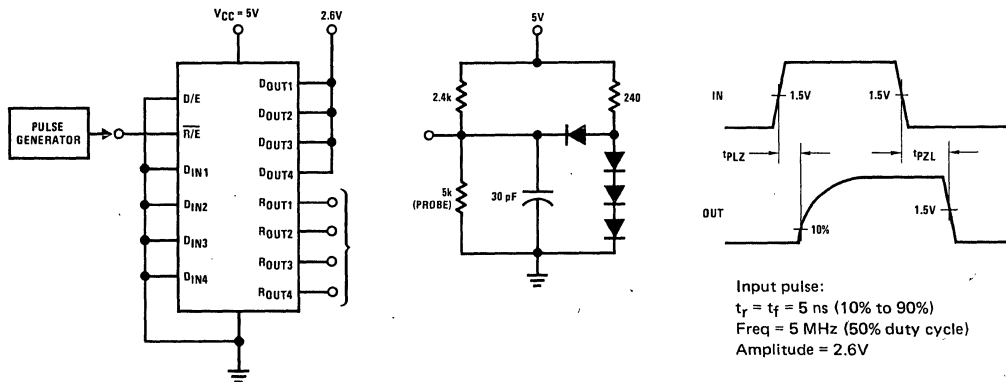


FIGURE 4. Propagation Delay (Receive/Enable to Receiver Output)



Section 3 Peripheral/Power Drivers

3

TEMPERATURE RANGE		DESCRIPTION	PAGE NUMBER
-55°C to +125°C	0°C to +70°C		
*DP7310	DP8310	Octal Latched Peripheral Drivers	3-4
*DP7311	DP8311	Octal Latched Peripheral Drivers	3-4
*DS1611	DS3611	Dual AND Peripheral Driver	3-11
*DS1612	DS3612	Dual NAND Peripheral Driver	3-11
*DS1613	DS3613	Dual OR Peripheral Driver	3-11
*DS1614	DS3614	Dual NOR Peripheral Driver	3-11
—	DS3616	Bubble Memory Coil Driver	3-17
*DS1631	DS3631	Dual AND CMOS Peripheral Driver	3-24
*DS1632	DS3632	Dual NAND CMOS Peripheral Driver	3-24
*DS1633	DS3633	Dual OR CMOS Peripheral Driver	3-24
*DS1634	DS3634	Dual NOR CMOS Peripheral Driver	3-24
—	DS3654	Printer Solenoid Driver	3-29
—	DS3656	Quad Peripheral Driver	3-33
—	DS3658	Quad High Current Peripheral Driver	3-35
—	DS3668	Quad High Current Peripheral Driver	3-38
—	DS3669	Quad High Current Peripheral Driver	3-41
—	DS3680	Quad Negative Voltage Relay Driver	3-44
—	DS3686	Dual Positive Voltage Relay Driver	3-47
*DS1687	DS3687	Dual Negative Voltage Relay Driver	3-49
—	DS75450	Dual AND Peripheral Driver	3-51
*DS55451	DS75451	Dual AND Peripheral Driver	3-51
*DS55452	DS75452	Dual NAND Peripheral Driver	3-51
*DS55453	DS75453	Dual OR Peripheral Driver	3-51
*DS55454	DS75454	Dual NOR Peripheral Driver	3-51
*DS55461	DS75461	Dual AND Peripheral Driver	3-62
*DS55462	DS75462	Dual NAND Peripheral Driver	3-62
*DS55463	DS75463	Dual OR Peripheral Driver	3-62
*DS55464	DS75464	Dual NOR Peripheral Driver	3-62
—	MM74C908	Dual CMOS 30V Driver	CMOS
—	MM74C918	Dual CMOS 30V Driver	CMOS
	AN-213	Safe Operating Areas for Peripheral Drivers	3-68

*Also available screened in accordance with MIL-STD-883 Class B. Refer to National Semiconductor's "The Reliability Handbook".

PERIPHERAL/POWER DRIVERS

Output High Voltage (V)	Latch-Up Voltage (Note 3) (V)	Output Low Voltage (V)	Output Low Current (mA)	Propagation Delay Typ (ns)	ON Power Supply Current (mA)	Drivers/Package	Input Compatibility (Logic)	Logic Function (Driver ON)	Device Number and Temperature Range		Page No.
									0°C to +70°C	-55°C to +125°C	
30		0.5	100	40	152	8	TTL	Note 5	DP8310	DP7310	3-4
30		0.5	100	40	125	8	TTL	Note 6	DP8311	DP7311	3-4
20	13.5	0.6	100	70	90	2	TTL	Note 7	DS3616		3-17
65	30	1.5	600		65	4	TTL/LS	NAND	DS3656		3-33
70	35	0.7	600	2430	65	4	TTL/LS	NAND	DS3658		3-35
70	Note 8	1.5	600	2000	80	4	TTL/LS	NAND	DS3668		3-38
70	35	0.7	600		65	4	TTL/LS	AND	DS3669		3-41
30	20	0.7	300	31	55	2	TTL	AND	DS75450		3-51
30	20	0.7	300	31	55	2	TTL	AND	DS75451	DS55451	3-51
30	20	0.7	300	31	55	2	TTL	NAND	DS75452	DS55452	3-51
30	20	0.7	300	31	55	2	TTL	OR	DS75453	DS55453	3-51
30	20	0.7	300	31	55	2	TTL	NOR	DS75454	DS55454	3-51
35	30	0.7	300	33	55	2	TTL	AND	DS75461	DS55461	3-62
35	30	0.7	300	33	55	2	TTL	NAND	DS75462	DS55462	3-62
35	30	0.7	300	33	55	2	TTL	OR	DS75463	DS55463	3-62
35	30	0.7	300	33	55	2	TTL	NOR	DS75464	DS55464	3-62
56	40	1.4	300	150	8	2	CMOS	AND	DS3631	DS1631	3-24
56	40	1.4	300	150	8	2	CMOS	NAND	DS3632	DS1632	3-24
56	40	1.4	300	150	8	2	CMOS	OR	DS3633	DS1633	3-24
56	40	1.4	300	150	8	2	CMOS	NOR	DS3634	DS1634	3-24
80	50	0.7	300	125	75	2	TTL/CMOS	AND	DS3611	DS1611	3-11
80	50	0.7	300	125	75	2	TTL/CMOS	NAND	DS3612	DS1612	3-11
80	50	0.7	300	125	75	2	TTL/CMOS	OR	DS3613	DS1613	3-11
80	50	0.7	300	125	75	2	TTL/CMOS	NOR	DS3614	DS1614	3-11
-2.1	-60	-60	-50	10,000	4.4	4	TTL/CMOS	(Note 4)	DS3680		3-44
(Note 1)	56	1.3	300	1000	28	2	TTL/CMOS	NAND	DS3686		3-47
(Note 1)	-56	-1.3	300	1000	28	2	TTL/CMOS	NAND	DS3687	DS1687	3-49
13.5	15	V _{CC} -1.8	300	150	0.015	2	CMOS	AND	MM74C908, MM74C918		CMOS CMOS
(Note 1)	45	1.6	250	1000	70	10	(Note 2)	(Note 2)	DS3654		3-29

Note 1: The DS3686, DS3687 and DS3654 contain an internal inductive fly-back clamp circuit connected from the output to ground. As an example, DS3686 driving a relay solenoid connected to 28V would clamp the output voltage fly-back transient at 56V caused by the solenoid's stored inductive current. This clamp protects the circuit output and quenches the fly-back.

Note 2: The DS3654 is a 10-bit shift register followed by 10 enabled drivers. The input circuit is equivalent to a 4k resistor to ground, and the logic input thresholds are 2.8V and 0.8V. The recommended power supply voltage is 7.5V to 9.5V. The circuit can be cascaded to be a 20 or 30-bit shift register.

Note 3: Latch-up voltage is the maximum voltage the output can sustain when switching an inductive load.

Note 4: DS3680 has a differential input circuit.

Note 5: DP8310 inverting, positive edge latching.

Note 6: DP8311 inverting, fall through latch.

Note 7: Bubble memory coil driver.

Note 8: DS3668 35V, latch-up with output fault protection.



DP7310/DP8310/DP7311/DP8311 Octal Latched Peripheral Drivers

General Description

The DP7310/8310, DP7311/8311 Octal Latched Peripheral Drivers provide the function of latching eight bits of data with open collector outputs, each driving up to 100mA DC with an operating voltage range of 30 volts. Both devices are designed for low input currents, high input/output voltages, and feature a power up clear (outputs off) function.

The DP7310/8310 are positive edge latching. Two active low write/enable inputs are available for convenient data bussing without external gating.

The DP7311/8311 are fall through latches. The active low strobe input latches data or allows fall through operation when held at logic "0". The latches are cleared (outputs off) with a logic "0" on the clear pin.

Features

- High current, high voltage open collector outputs
- Low current, high voltage inputs
- All outputs simultaneously sink rated current "DC" with no thermal derating at maximum rated temperature.

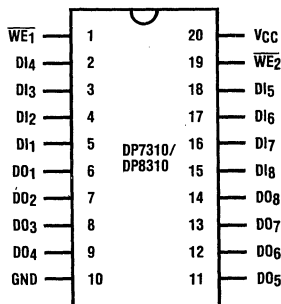
- Parallel latching or buffering
- Separate active low enables for easy data bussing
- Internal "glitch free" power up clear
- 10% V_{CC} tolerance

Applications

- High current high voltage drivers
- Relay drivers
- Lamp drivers
- LED drivers
- TRIAC drivers
- Solenoid drivers
- Stepper motor drivers
- Level translators
- Fiber-optic LED drivers

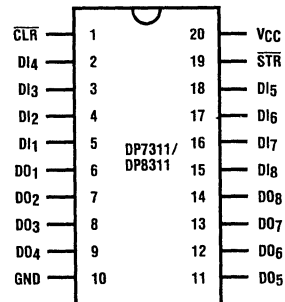
Connection Diagrams

Dual-In-Line Package



TUF5246

Dual-In-Line Package



TUF5246

Order Number DP7310J, DP7311J,
DP8310J, DP8311J, DP8310N
or DP8311N
See NS Package J20A or N20A

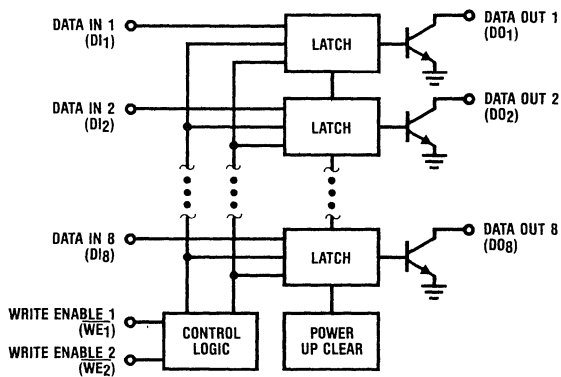
Logic Table

DP7310/DP8310			
Write Enable 1 WE ₁	Write Enable 2 WE ₂	Data Input DI ₁₋₈	Data Output DO ₁₋₈
0	0	X	Q
0	↗	0	1
0	↗	1	0
↗	0	0	1
↗	0	1	0
0	1	X	Q
1	0	X	Q
1	1	X	Q

DP7311/DP8311			
Clear CLR	Strobe STR	Data Input DI ₁₋₈	Data Output DO ₁₋₈
1	1	X	Q
1	0	0	1
1	0	1	0
0	X	X	1

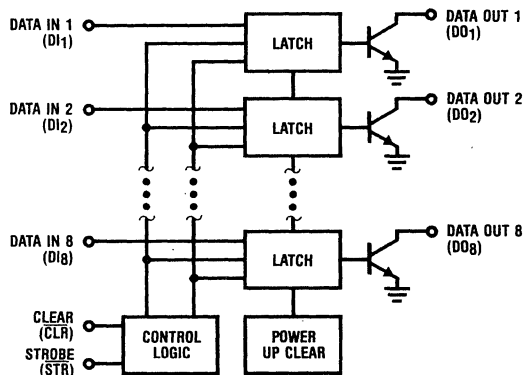
X = Don't Care
 1 = Outputs Off
 0 = Outputs On
 Q = Pre-existing Output
 ↗ = Positive Edge Transition

Block Diagram DP7310/DP8310



TL/F5246

Block Diagram DP7311/DP8311



TL/F5246

Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Input Voltage	35V
Output Voltage	35V
Maximum Power Dissipation* at 25°C	
Cavity Package	1821 mW
Molded Package	2005 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

* Derate cavity package 12.1 mW/°C above 25°C; derate molded package 16.0 mW/°C above 25°C.

Operating Conditions

	Min.	Max.	Units
Supply Voltage (V _{CC})	4.5	5.5	V
Temperature			
DP7310/DP7311	-55	+125	°C
DP8310/DP8311	0	+70	°C
Input Voltage		30	V
Output Voltage		30	V

DC Electrical Characteristics DP7310/DP8310, DP7311/DP8311 (Notes 2 and 3)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V _{IH}	Logical "1" Input Voltage		2.0			V
V _{IL}	Logical "0" Input Voltage				0.8	V
V _{OL}	Logical "0" Output Voltage	Data outputs latched to logical "0", V _{CC} = min. I _{OL} = 75 ma I _{OL} = 100 mA		0.35	0.4 0.5	V V
I _{OH}	Logical "1" Output Current	Data outputs latched to logical "1", V _{CC} = min. V _{OH} = 25V V _{OH} = 30V		2.5	500 250	μA μA
I _{IH}	Logical "1" Input Current	V _{IH} = 2.7V, V _{CC} = max.		0.1	25	μA
I _I	Input Current at Maximum Input Voltage	V _{IN} = 30V, V _{CC} = max.		1	250	μA
I _{IL}	Logical "0" Input Current	V _{IN} = 0.4V, V _{CC} = max.		-215	-300	μA
V _{clamp}	Input Clamp Voltage	I _{IN} = -12 mA		-0.8	-1.5	V
I _{CC0}	Supply Current, Outputs On	Data outputs latched to a logical "0". All inputs are at logical "1", V _{CC} = max.		100 100 88 88	125 152 117 125	mA mA mA mA
I _{CC1}	Supply Current, Outputs Off	Data outputs latched to a logic "1". Other conditions same as I _{CC0} .		40 40 25 25	47 57 34 36	mA mA mA mA

AC Electrical Characteristics DP7310/DP8310: $V_{CC} = 4.5V$, $T_A = -55^{\circ}C$ to $125^{\circ}C$

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
t_{pd0}	High to Low Propagation Delay Write Enable Input to Output	Figure 1		40	120	ns
t_{pd1}	Low to High Propagation Delay Write Enable Input to Output	Figure 1		70	150	ns
t_{SETUP}	Minimum Set-Up Time Data In to Write Enable Input	$t_{HOLD} = 0ns$ Figure 1	45	20		ns
t_{pWH} , t_{pWL}	Minimum Write Enable Pulse W'dth	Figure 1	60	25		ns
t_{THL}	High to Low Output Transition Time	Figure 1		16	35	ns
t_{TLH}	Low to High Output Transition Time	Figure 1		38	70	ns
C_{IN}	"N" Package Note 4			5	15	pF

AC Electrical Characteristics DP7311/DP8311: $V_{CC} = 5V$, $T_A = 25^{\circ}C$

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
t_{pd0}	High to Low Propagation Delay Data In to Output	Figure 2		30	60	ns
t_{pd1}	Low to High Propagation Delay Data In to Output	Figure 2		70	100	ns
t_{SETUP}	Minimum Set-Up Time Data In to Strobe Input	$t_{HOLD} = 0ns$ Figure 2	0	-25		ns
t_{pWL}	Minimum Strobe Enable Pulse Width	Figure 2	60	35		ns
t_{pdC}	Propagation Delay Clear to Data Output	Figure 2		70	135	ns
t_{pWC}	Minimum Clear Input Pulse Width	Figure 2	60	25		ns
t_{THL}	High to Low Output Transition Time	Figure 2		20	35	ns
t_{TLH}	Low to High Output Transition Time	Figure 2		38	60	ns
C_{IN}	Input Capacitance — Any Input	Note 4		5	15	pF

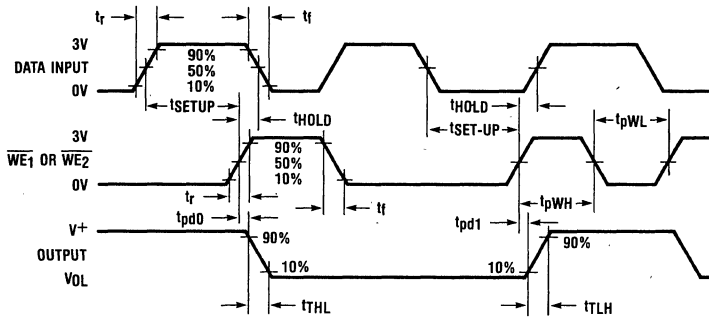
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min./max. limits apply across the $-55^{\circ}C$ to $+125^{\circ}C$ temperature range for the DP7310/DP7311 and across the $0^{\circ}C$ to $+70^{\circ}C$ for the DP8310/DP8311. All typical values are for $T_A = 25^{\circ}C$, $V_{CC} = 5V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted.

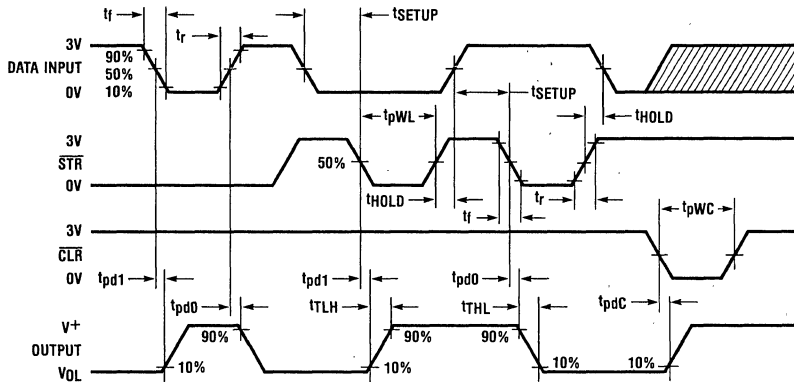
Note 4: Input capacitance is guaranteed by periodic testing. $f_{TEST} = 10kHz$ at $300mV$, $T_A = 25^{\circ}C$

Switching Time Waveform DP7310/DP8310



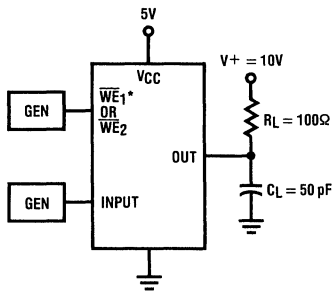
TUF5246

Switching Time Waveform DP7311/DP8311



TUF5246

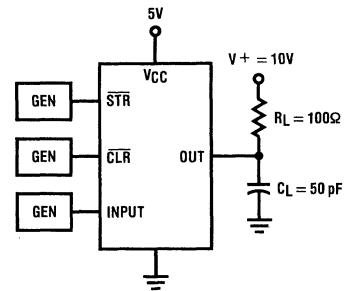
Switching Time Test Circuits DP7310/DP8310 DP7311/DP8311



* $\overline{WE}_1 = 0V$ WHEN THE INPUT = \overline{WE}_2

TUF5246

FIGURE 1



PULSE GENERATOR CHARACTERISTICS:
 $Z_0 = 50\Omega$, $t_r = t_f = 5\text{ ns}$

TUF5246

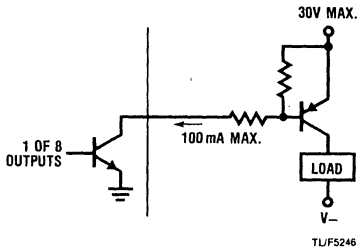
FIGURE 2

Typical Applications DP8310/11 Buffering High Current Device (Notes 1 and 2)

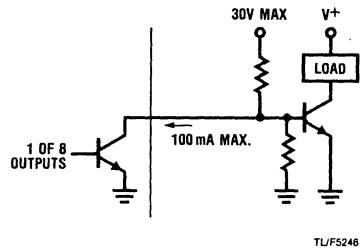
DP7310/8310/7311/8311



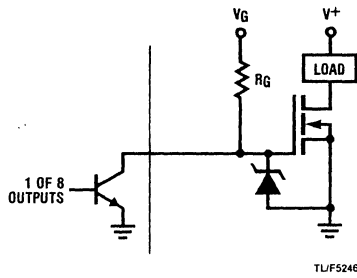
PNP High Current Driver



NPN High Current Driver

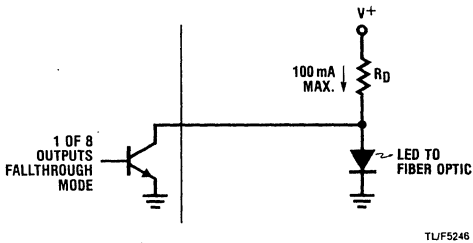


VMOS High Current Driver

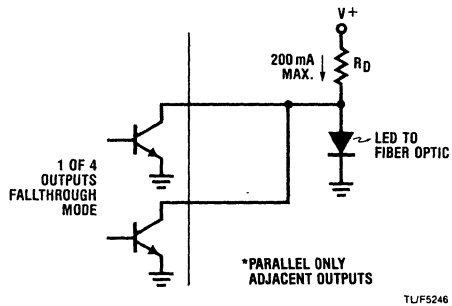


Eight Output/Four Output Fiber Optic LED Driver

DP8311 100 mA Drivers

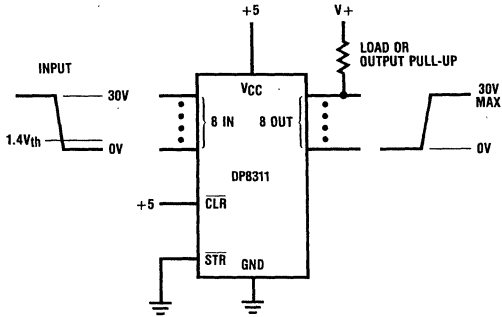


DP8311 Parallel Outputs (200 mA) Drivers*



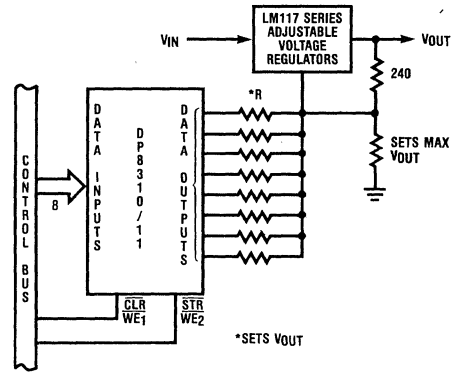
Typical Applications (cont'd)

8-Bit Level Translator-Driver



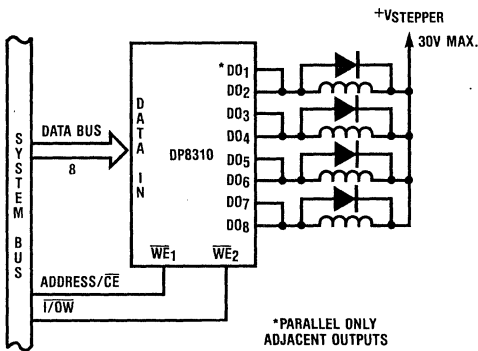
TLF5246

Digital Controlled 256 Level Power Supply from 1.2 Volts to 30 Volts



TLF5246

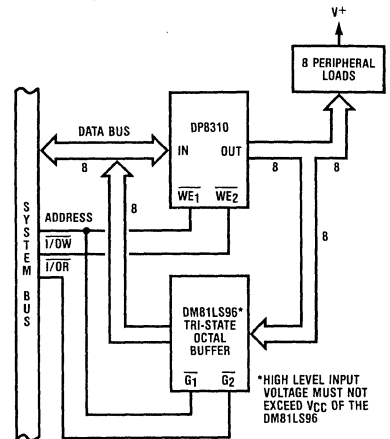
200 mA Drive for a 4 Phase Bifilar Stepper Motor



*PARALLEL ONLY
ADJACENT OUTPUTS

TLF5246

Reading the State of the Latched Peripherals



*HIGH LEVEL INPUT
VOLTAGE MUST NOT
EXCEED VCC OF THE
DM81LS96

TLF5246

Note 1: Always use good V_{CC} bypass and ground techniques to suppress transients caused by peripheral loads.

Note 2: Printed circuit board mounting is required if these devices are operated at maximum rated temperature and current (all outputs on DC).

DS1611/DS3611, DS1612/DS3612, DS1613/DS3613, DS1614/DS3614 Dual Peripheral Drivers

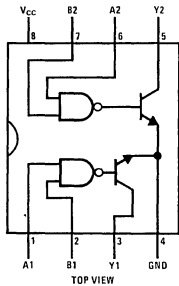
General Description

The DS1611 series of dual peripheral drivers was designed for those applications where a higher breakdown voltage is required than that provided by the DS75451 series. The pin outs for the circuits are identical to those of the DS75451 through DS75454. The DS1611 series parts feature high voltage outputs (80V breakdown in the "OFF" state) as well as high current (300 mA in the "ON" state). Typical applications include power drivers, relay drivers, lamp drivers, MOS drivers, and memory drivers.

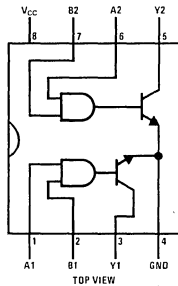
Features

- 300 mA output current capability per driver
- High voltage outputs (80V)
- TTL compatible
- Input clamping diodes
- Choice of logic function

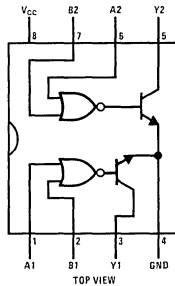
Connection Diagrams (Dual-In-Line and Metal Can Packages)



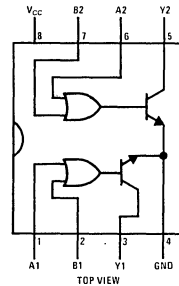
Order Number DS1611J-8,
DS3611J-8 or DS3611N



Order Number DS1612J-8,
DS3612J-8 or DS3612N

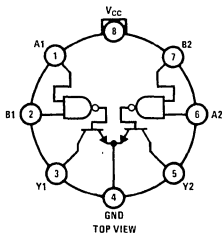


Order Number DS1613J-8,
DS3613J-8 or DS3613N



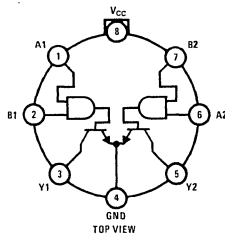
Order Number DS1614J-8,
DS3614J-8 or DS3614N

See NS Package J08A or N08A



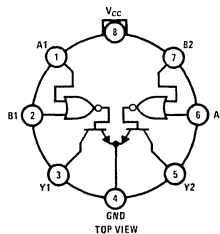
Pin 4 is in electrical contact with the case.

Order Number
DS1611H or DS3611H



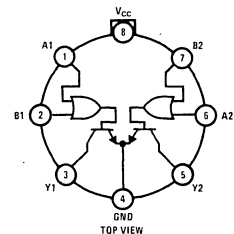
Pin 4 is in electrical contact with the case.

Order Number
DS1612H or DS3612H



Pin 4 is in electrical contact with the case.

Order Number
DS1613H or DS3613H



Pin 4 is in electrical contact with the case.

Order Number
DS1614H or DS3614H

See NS Package H08C

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Output Voltage (Note 5)	80V
Continuous Output Current	300 mA
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1133 mW
Molded Package	1022 mW
TO-5 Package	787 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})			
DS161X	4.5	5.5	V
DS361X	4.75	5.25	V
Temperature (T_A)			
DS161X	-55	+125	°C
DS361X	0	+70	°C

*Derate cavity package 7.6 mW/°C above 25°C; derate molded package 8.2 mW/°C above 25°C; derate TO-5 package 5.25 mW/°C above 25°C.

Electrical Characteristics DS1611/DS3611, DS1612/DS3612, DS1613/DS3613, DS1614/DS3614 (Notes 2 and 3)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
V_{IH}	High Level Input Voltage	(Figure 1)	2			V	
V_{IL}	Low Level Input Voltage	(Figure 2)			0.8	V	
V_I	Input Clamp Voltage	$V_{CC} = \text{Min}$, $I_I = -12 \text{ mA}$, (Figure 3)	-1.2		-1.5	V	
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}$, (Figure 1)	DS1611, $V_{IL} = 0.8V$	$I_{OL} = 100 \text{ mA}$	0.2	0.5	V
				$I_{OL} = 300 \text{ mA}$	0.45	0.8	V
			DS1612, $V_{IH} = 2V$	$I_{OL} = 100 \text{ mA}$	0.2	0.5	V
				$I_{OL} = 300 \text{ mA}$	0.45	0.8	V
			DS1613, $V_{IL} = 0.8V$	$I_{OL} = 100 \text{ mA}$	0.2	0.5	V
				$I_{OL} = 300 \text{ mA}$	0.45	0.8	V
			DS1614, $V_{IH} = 2V$	$I_{OL} = 100 \text{ mA}$	0.2	0.5	V
				$I_{OL} = 300 \text{ mA}$	0.45	0.8	V
			DS3611, $V_{IL} = 0.8V$	$I_{OL} = 100 \text{ mA}$	0.2	0.4	V
				$I_{OL} = 300 \text{ mA}$	0.45	0.7	V
			DS3612, $V_{IH} = 2V$	$I_{OL} = 100 \text{ mA}$	0.2	0.4	V
				$I_{OL} = 300 \text{ mA}$	0.45	0.7	V
DS3613, $V_{IL} = 0.8V$	$I_{OL} = 100 \text{ mA}$	0.2	0.4	V			
	$I_{OL} = 300 \text{ mA}$	0.45	0.7	V			
DS3614, $V_{IH} = 2V$	$I_{OL} = 100 \text{ mA}$	0.2	0.4	V			
	$I_{OL} = 300 \text{ mA}$	0.45	0.7	V			
V_{OH}	Output Breakdown Voltage	$V_{CC} = \text{Min}$, (Figure 1)	$V_{IH} = 2V$, $I_{OH} = 300 \mu A$	DS1611, DS1613	80		V
			$V_{IH} = 2V$, $I_{OH} = 100 \mu A$	DS3611, DS3613	80		V
			$V_{IL} = 0.8V$, $I_{OH} = 300 \mu A$	DS1612, DS1614	80		V
			$V_{IL} = 0.8V$, $I_{OH} = 100 \mu A$	DS3612, DS3614	80		V
I_I	Input Current at Maximum Input Voltage	$V_{CC} = \text{Max}$, $V_I = 5.5V$, (Figure 2)			1	mA	
I_{IH}	High Level Input Current	$V_{CC} = \text{Max}$, $V_I = 2.4V$, (Figure 2)			40	μA	
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max}$, $V_I = 0.4V$, (Figure 3)		-1	-1.6	mA	
I_{CCH}	Supply Current	$V_{CC} = \text{Max}$, Outputs High, (Figures 4 and 5)	$V_I = 5V$	DS1611/ DS3611		11	mA
				DS1613/ DS3613		14	mA
			$V_I = 0V$	DS1612/ DS3612		14	mA
				DS1614/ DS3614		17	mA
I_{CCL}	Supply Current	$V_{CC} = \text{Max}$, Outputs Low, (Figures 4 and 5)	$V_I = 0V$	DS1611/ DS3611		69	mA
				DS1613/ DS3613		73	mA
			$V_I = 5V$	DS1612/ DS3612		71	mA
				DS1614/ DS3614		79	mA

Switching Characteristics $V_{CC} = 5.0V, T_A = 25^\circ C$

DS1611/DS3611, DS1612/DS3612, DS1613/DS3613, DS1614/DS3614

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
t_{PD1}	Propagation Delay Time, Low-To-High Level Output	$I_O \approx 200 \text{ mA}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 6)	DS1611/ DS3611		130	ns
			DS1612/ DS3612		110	ns
			DS1613/ DS3613		125	ns
			DS1614/ DS3614		220	ns
t_{PD0}	Propagation Delay Time, High-To-Low Level Output	$I_O \approx 200 \text{ mA}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 6)	DS1611/ DS3611		125	ns
			DS1612/ DS3612		110	ns
			DS1613/ DS3613		125	ns
			DS1614/ DS3614		150	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the $0^\circ C$ to $+70^\circ C$ temperature range for the DS3611, DS3612, DS3613, DS3614, and $-55^\circ C$ to $+125^\circ C$ temperature range for the DS1611, DS1612, DS1613 and DS1614. All typical values are for $T_A = 25^\circ C$ and $V_{CC} = 5V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Maximum junction temperature is $150^\circ C$.

Note 5: Maximum voltage to be applied to either output in the "OFF" state.

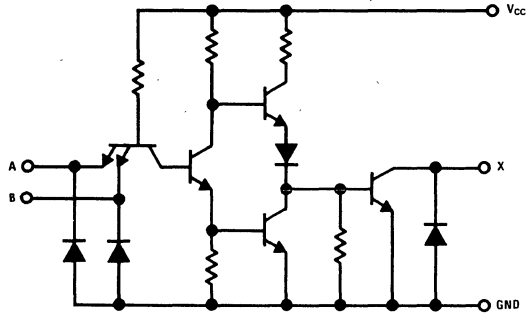
Note 6: Delay is measured with a 50Ω load to 10V, 15 pF load capacitance, measured from 1.5V input to 50% point on output.

DS1611/DS3611, DS1612/DS3612,
DS1613/DS3613, DS1614/DS3614

3

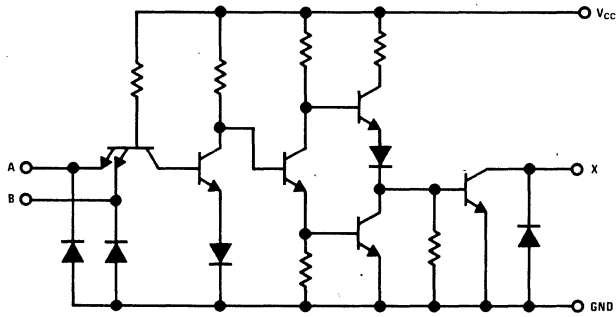
Schematic Diagrams (each driver)

DS3611 Dual AND Peripheral Driver



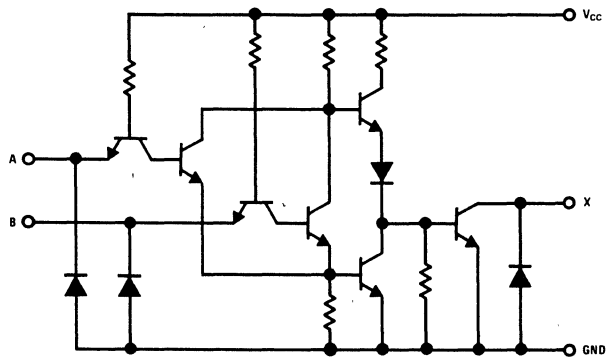
Note: 1/2 of unit shown.

DS3612 Dual NAND Peripheral Driver



Note: 1/2 of unit shown.

DS3613 Dual OR Peripheral Driver

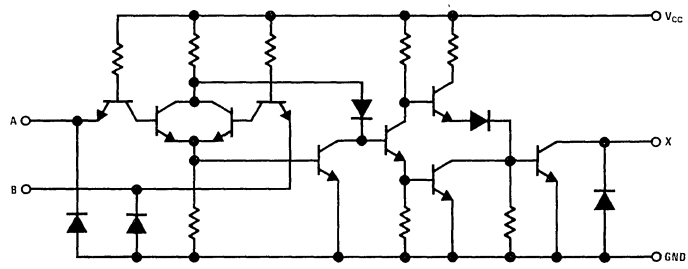


Note: 1/2 of unit shown.



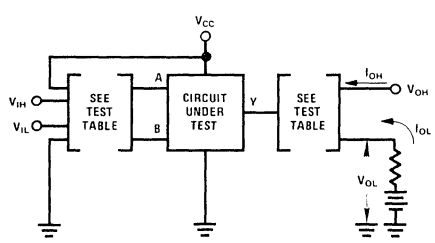
Schematic Diagrams (Continued)

DS3614 Dual NOR Peripheral Driver



Note: 1/2 of unit shown.

Test Circuits



CIRCUIT	INPUT UNDER TEST	OTHER INPUT	OUTPUT	
			APPLY	MEASURE
DS3611	VIH VIL	VIH Vcc	IOH IOL	VOH VOL
DS3612	VIH VIL	VIH Vcc	IOL IOH	VOL VOH
DS3613	VIH VIL	GND VIL	IOH IOL	VOH VOL
DS3614	VIH VIL	GND VIL	IOL IOH	VOL VOH

NOTE: Each input is tested separately.

FIGURE 1. VIH, VIL, VOH, VOL

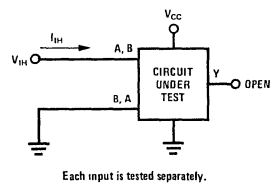
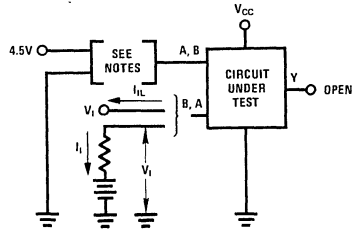


FIGURE 2. Ii, IiH



Note 1: Each input is tested separately.
Note 2: When testing DS3613 and DS3614 input not under test is grounded. For all other circuits it is at 4.5V.

FIGURE 3. Vi, IiL

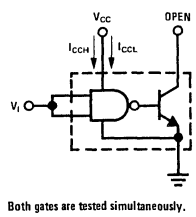


FIGURE 4. ICCH, ICCL for AND, NAND Circuits

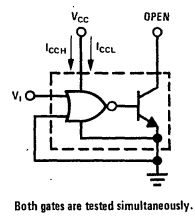
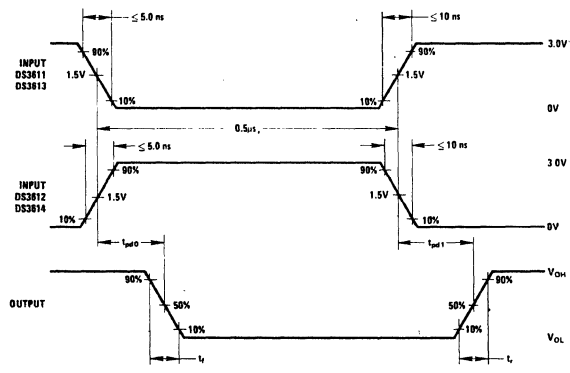
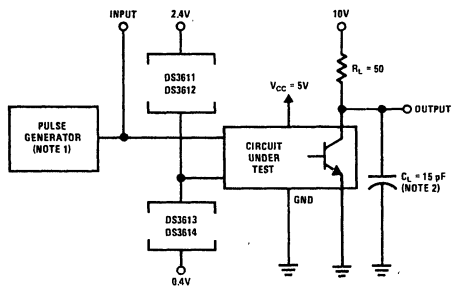


FIGURE 5. ICCH, ICCL for OR, NOR Circuits

Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: PRR = 1.0 MHz, $Z_{OUT} \approx 50\Omega$.
 Note 2: C_L includes probe and jig capacitance.

FIGURE 6. Switching Times of Complete Drivers

DS3616 Bubble Memory Coil Driver

General Description

The DS3616 bubble memory coil driver provides the function of driving the high current coils of a bubble memory device. The control inputs A, B, \overline{CS} and HLD-EN are TTL compatible to insure easy interfacing to MOS control circuits. Internal logic controls the output sinking and sourcing transistors to drive the X and Y bubble memory coils in a bridged push-pull configuration.

Sourcing transistors are driven into saturation by the on-chip voltage booster for maximum current drive to the coil.

The internal power up/down control circuit prevents glitches and noise on the outputs during system initialization.

\overline{CS} enables the output drive transistors. A pause capability is available from the HLD-EN input to allow asynchronous operation (refer to Typical Applications data).

The DS3616 is characterized to operate from 0°C to 70°C.

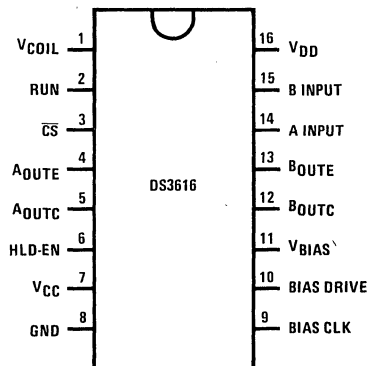
Features

- Two high current push-pull outputs
- TTL compatible low current inputs
- Two power supplies +5V and +12V
- Internal clamp diodes
- Power up/down control circuit
- Optional internal voltage booster
- Run output for function driver control

3

Connection Diagram

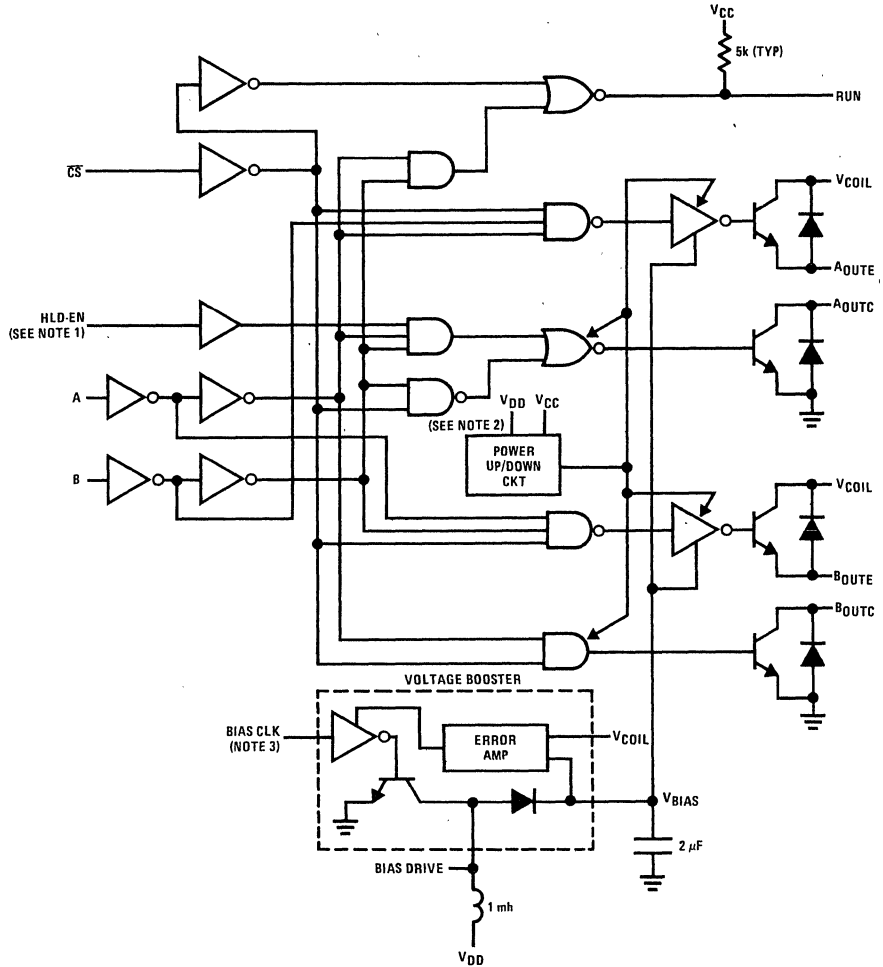
Dual-In-Line Package



TOP VIEW

Order Number DS3616N
See NS Package N16A

Functional Block Diagram



Functional Tables (Note 2)

HLD-EN = 0					
A	B	\overline{CS}	A _{OUT}	B _{OUT}	Run
X	X	1	Z	Z	0
0	0	0	Z	Z	1
0	1	0	0	1	1
1	0	0	1	0	1
1	1	0	0	0	0

HLD-EN = 1					
A	B	\overline{CS}	A _{OUT}	B _{OUT}	Run
X	X	1	Z	Z	0
0	0	0	Z	Z	1
0	1	0	0	1	1
1	0	0	1	0	1
1	1	0	Z	0	0

Note 1: When used as Y driver, HLD-EN is in Logic "0" state.

Note 2: Run output is independent of the power-up clear circuit and functions down to $V_{CC} = 3V$. (See Typical Applications.)

Note 3: If BIAS CLK stops, it must remain in a Logic "1" state to prevent excessive DC current in the inductor.

Absolute Maximum Ratings (Note 1)

Supply Voltage (V_{CC})	7V
Supply Voltage (V_{DD})	15V
Coil Source Voltage (V_{COIL})	14V
$V_{BIAS}-V_{COIL}$	6.5V
Peak Output Current (Coil Outputs)	1A
V_{BIAS} Drive Current	300 mA
Maximum Power Dissipation* at 25°C Molded Package	1950 mW

*Derate molded package 15.6 mW/°C above 25°C.

Recommended Operating Conditions

	Min	Typ	Max	Units
T_A Operating Temperature	0	70		°C
Supply Voltage (V_{CC})	4.75 (4.5)**	5	5.25	V
Supply Voltage (V_{DD})	11.4 (10.8)**	12	12.6	V
Coil Source Voltage (V_{COIL})	7	10	13.5	V
$V_{BIAS}-V_{COIL}$	4.0	4.8	6	V
Peak Coil Output Current			950	mA
Peak V_{BIAS} Drive Current			200	mA

** Min supply voltage for functionality during power up/down sequences.

Electrical Characteristics (Notes 2 and 3)

Parameter		Conditions	Min	Typ	Max	Units
V_{IH}	High Level Input Voltage	$V_{CC} = 4.75V$	2.0			V
V_{IL}	Low Level Input Voltage	$V_{CC} = 4.75V$			0.8	V
V_{OD}	Differential Output Voltage	$I_O = 850$ mA, $V_{COIL} = 13.5V$, $V_{BIAS} = 18.5V$, $V_{CC} = 4.75V$, $V_{DD} = 11.4V$	11.7	12.2	12.7	V
V_{OCLAMP}	Output Clamp Diode Voltage	$I_O = -850$ mA, Lower Clamp	-0.9		-1.5	V
		$I_O = 850$ mA, Upper Clamp	0.9		1.5	V
V_{ICLAMP}	Input Clamp Diode Voltage	$I_I = -12$ mA		-0.9	-1.5	V
V_{OHR}	Run High Level Output Voltage	$I_{OH} = -400$ μ A, $V_{CC} = 4.75V$	2.4	3.3		V
		$I_{OH} = -100$ μ A, $V_{CC} = 4.75V$	3.5	4.1	4.45	V
V_{OLR}	Run Low Level Output Voltage	$I_{OL} = 5$ mA, $V_{CC} = 4.75V$		0.2	0.5	V
I_I	Maximum Input Current at Maximum Input Voltage	$V_{CC} = 5.25V$, $V_{IN} = 5.5V$		1	100	μ A
I_{IH}	High Level Input Current	$V_{CC} = 5.25V$, $V_{IN} = 2.4V$		1	40	μ A
I_{IL}	Low Level Input Current	$V_{CC} = 5.25V$, $V_{IL} = 0.4V$		-160	-250	μ A
V_{CCEN}	V_{CC} Power Up Enable Voltage		3.2	3.8	4.4	V
V_{DDEN}	V_{DD} Power Up Enable Voltage		8.0	9.5	10.5	V
V_{BIAS}	Regulator Threshold Voltage	$V_{COIL} = 10V$, $V_{DD} = 12V$, $V_{CC} = 5V$	14.0	14.8	16	V
V_F	Bias Diode Voltage	$I_F = 100$ mA		0.9	1.5	V
I_R	Bias Diode Leakage Current	$V_{REVERSE} = 20V$		5	500	μ A
V_{OL}	$V_{CE(SAT)}$ of V_{BIAS} Output Transistor	$V_{CC} = 4.75V$, Bias Drive = 100 mA		0.3	0.6	V
I_{OFF}	Leakage Current of V_{BIAS} Output Transistor	$V_{OH} = 20V$		5	500	μ A
I_{LCU}	Leakage Current of the Upper Drive	$V_{COIL} = 13.5V$, $V_{OUT} = 0V$		10	1000	μ A
I_{LCL}	Leakage Current of the Lower Drive	$V_{OUT} = 15V$		10	1000	μ A
$I_{CC1(E)}$	V_{CC} Supply Current Chip Enabled	A = 3.0V, B = 0.4V, $\overline{CS} = 0.4V$, HLD-EN = 0.4V, $V_{CC} = 5.25V$		55	90	mA
$I_{CC0(D)}$	V_{CC} Supply Current Chip Disabled	A = B = HLD-EN = 0.4V, $\overline{CS} = 3.0V$, $V_{CC} = 5.25V$		17	33	mA
I_{DD}	V_{DD} Supply Current	$V_{DD} = 12.6V$		4.5	7	mA
$I_{BIAS1(E)}$	V_{BIAS} Current Chip Enabled	$V_{BIAS} = 18.5V$, $V_{COIL} = 13.5V$ Same Input Conditions as I_{CC1}		40	60	mA
$I_{BIAS0(D)}$	V_{BIAS} Current Chip Disabled	$V_{BIAS} = 18.5V$, $V_{COIL} = 13.5V$ Same Input Conditions as I_{CC0}		5	8	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to 70°C temperature range for the DS3616. $V_{CC} = 5V \pm 5\%$, $V_{DD} = 12V \pm 5\%$. During power up/down, for functional operation, $V_{CC} = +5\%$, -10% ; $V_{DD} = +5\%$, -10% .

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Switching Characteristics $T_A = 0^\circ\text{C}$ to 70°C , $V_{CC} = 4.75\text{V}$, $V_{DD} = 11.4\text{V}$

Parameter		Conditions	Min	Typ	Max	Units
$t_{R(E)}$	Rise Time for A_{OUT} or B_{OUT} Emitters	Figure 1		40	100	ns
$t_{F(E)}$	Fall Time for A_{OUT} or B_{OUT} Emitters			15	50	ns
$t_{R(C)}$	Rise Time for A_{OUT} or B_{OUT} Collectors	Figure 2		15	50	ns
$t_{F(C)}$	Fall Time for A_{OUT} or B_{OUT} Collectors			25	50	ns
$t_{ON(E)}$	Turn ON Time for A_{OUT} or B_{OUT} Emitters	Figure 1		85	150	ns
$t_{OFF(E)}$	Turn OFF Time for A_{OUT} or B_{OUT} Emitters			45	120	ns
$t_{ON(C)}$	Turn ON Time for A_{OUT} or B_{OUT} Collectors	Figure 2		70	150	ns
$t_{OFF(C)}$	Turn OFF Time for A_{OUT} or B_{OUT} Collectors			55	120	ns
$t_{CSON(E)}$	Time for \overline{CS} to Enable Output Emitters	Figure 3		70	150	ns
$t_{CSOFF(E)}$	Time for \overline{CS} to TRI-STATE® Output Emitters			50	120	ns
$t_{CSON(C)}$	Time for \overline{CS} to Enable Output Collectors	Figure 4		50	120	ns
$t_{CSOFF(C)}$	Time for \overline{CS} to TRI-STATE Output Collectors			60	120	ns
$t_{R(RUN)}$	Rise Time for Run Output	Figure 5		50	70	ns
$t_{F(RUN)}$	Fall Time for Run Output			10	20	ns
$t_{ON(RUN)}$	Turn ON Time for Run Output			70	110	ns
$t_{OFF(RUN)}$	Turn OFF Time for Run Output			40	70	ns
t_{PLZ}	Propagation Delay for HLD-EN to TRI-STATE A_{OUT} Collector	Figure 6		65	120	ns
t_{PZL}	Propagation Delay for HLD-EN Turn ON A_{OUT} Collector			45	120	ns
t_{CHARGE}	Charge Up Time for V_{BIAS}	1 mh, 2 μF , $f_{CLK} = 800$ kHz		2	5	ms
t_{JON}	Turn ON Time of Clamp Diodes	Figure 7		30	50	ns
IMB	DC Imbalance under AC Conditions	Figure 8		± 0.1		V
BIAS CLK	Duty Cycle		40	50	60	%
	Frequency		600	800	1000	kHz

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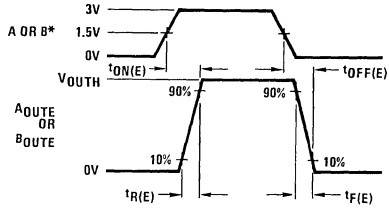
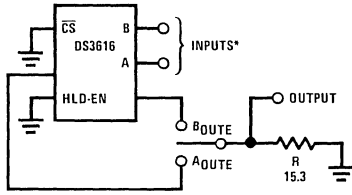
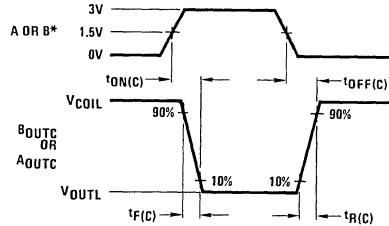
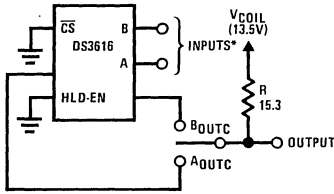
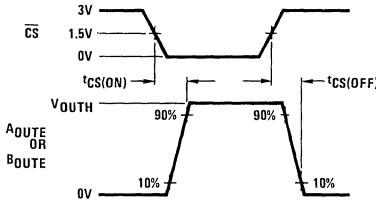
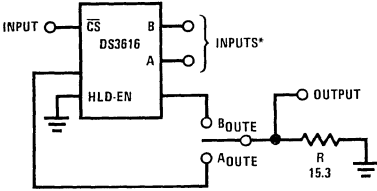


FIGURE 1. Test Set-Up and Timing Waveforms for A_{OUT} and B_{OUT} Emitters



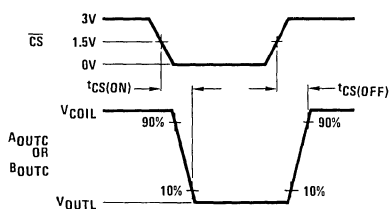
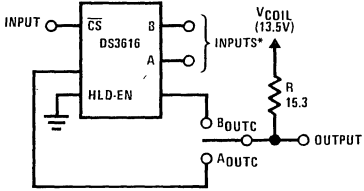
* Ground A input if B is the driven input or Ground B if A is the driven input.

FIGURE 2. Test Set-Up and Timing Waveforms for A_{OUT} and B_{OUT} Collectors



* For A_{OUT} and B_{OUTC}, A = 3V, B = 0V;
for B_{OUT} and A_{OUTC}, A = 0V, B = 3V.

FIGURE 3. Test Set-Up and Timing Waveforms for A_{OUT} and B_{OUT} Emitters



* For A_{OUT} and B_{OUTC}, A = 3V, B = 0V;
for B_{OUT} and A_{OUTC}, A = 0V, B = 3V.

FIGURE 4. Test Set-Up and Timing Waveforms for A_{OUT} and B_{OUT} Collectors

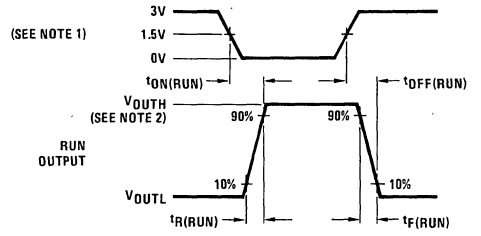
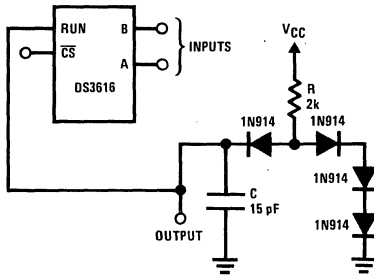
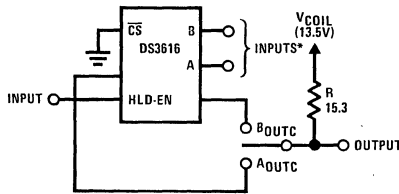


FIGURE 5. Test Set-Up and Timing Waveforms for Run Output



* Input Conditions: A = B = 3V

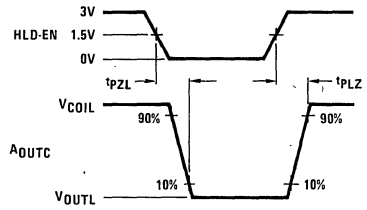


FIGURE 6. Test Set-Up and Timing Waveforms for A_{OUTC} TRI-STATE

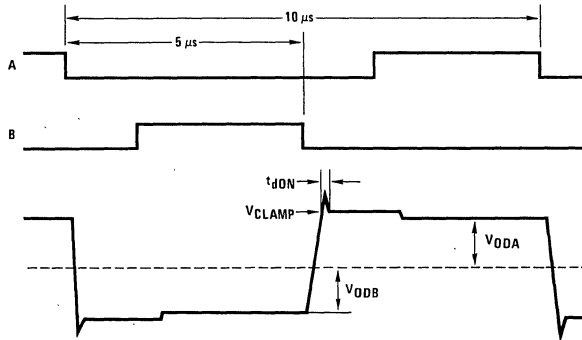


FIGURE 7. AC Switching Characteristics

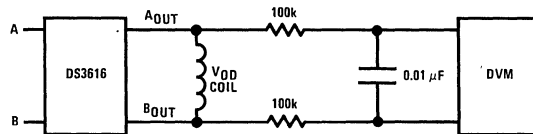


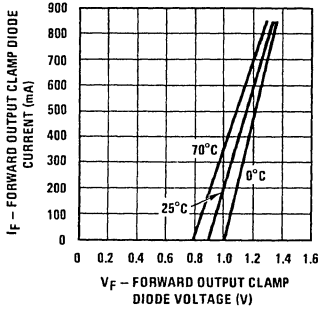
FIGURE 8. DC Imbalance Test Circuit

Note 1: Output waveforms may be generated with \overline{CS} = input, A = B = 0V or B = input, A = 3V, \overline{CS} = 0V

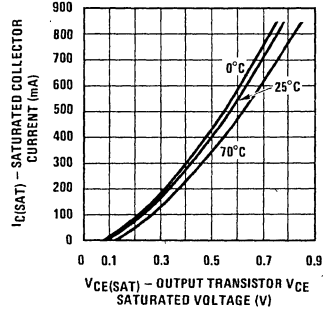
Note 2: Reference V_{OUTH} is set at 4V, which includes the active pull-up voltage plus charge-up voltage due to the internal 5 kΩ resistor to V_{CC} (typical rise time = 12 ns).

Typical Characteristics

I_F vs V_F of Output Clamp Diode Over Ambient Temperature



$I_{C(SAT)}$ vs $V_{CE(SAT)}$ of Output Transistors Over Ambient Temperature



Typical Applications (Figures 9 and 10)

The coil driver circuit is used to generate triangular current waveforms for the bubble memory coils. The currents are generated by switching the coil driver in such a way that a voltage pulse is applied to the coil. The coil inductance integrates the voltage into a current ramp. When the pulse is switched OFF the current is commutated by two on-chip clamp diodes and current ramps down to zero. At that time the opposite polarity pulse is applied to the coil, which causes the current to ramp in the opposite direction.

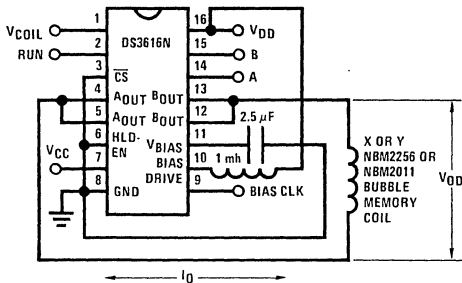


FIGURE 9. Typical Application

The Run output drives the chip enable input of the function driver (DS3615). It goes low when $A = B = 1$, indicating the controller has stopped the coils, or when $\overline{CS} = 1$ indicating the bubble is not selected. In the event of a system power loss, A and B are to be set to logic 1 by the controller. This stops the coil driver and causes the Run output to go to zero which disables the function driver. The Run output is guaranteed to stay at Logic "0" and coil drive outputs in Logic "0" state or high impedance condition (if $A = B = 1$ or $\overline{CS} = 1$) down to $V_{CC} = 3V$, at which time the function driver and coil driver power supply sensors will have disabled all outputs driving the bubble.

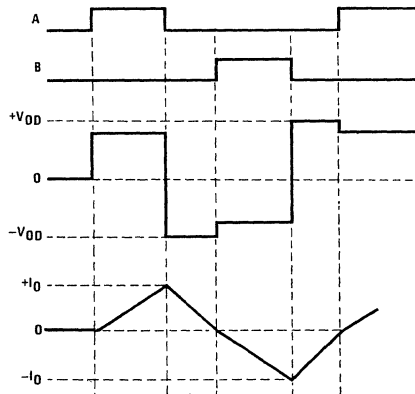


FIGURE 10. Coil Current and Voltage Waveforms

DS1631/DS3631, DS1632/DS3632, DS1633/DS3633, DS1634/DS3634 CMOS Dual Peripheral Drivers

General Description

The DS1631 series of dual peripheral drivers was designed to be a universal set of interface components for CMOS circuits.

Each circuit has CMOS compatible inputs with thresholds that track as a function of V_{CC} (approximately $1/2 V_{CC}$). The inputs are PNP's providing the high impedance necessary for interfacing with CMOS.

Outputs have high voltage capability, minimum breakdown voltage is 56V at 250 μ A.

The outputs are Darlington connected transistors. This allows high current operation (300 mA max) at low internal V_{CC} current levels since base drive for the output transistor is obtained from the load in proportion to the required loading conditions. This is essential in order to minimize loading on the CMOS logic supply.

Typical $V_{CC} = 5V$ power is 28 mW with both outputs ON. V_{CC} operating range is 4.5V to 15V.

The circuit also features output transistor protection if the V_{CC} supply is lost by forcing the output into the

high impedance OFF state with the same breakdown levels as when V_{CC} was applied.

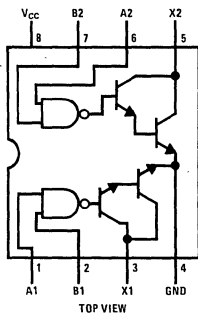
Pin-outs are the same as the respective logic functions found in the following popular series of circuits: DS75451, DS75461, DS3611. This feature allows direct conversion of present systems to the MM74C CMOS family and DS1631 series circuits with great power savings.

The DS1631 series is also TTL compatible at $V_{CC} = 5V$.

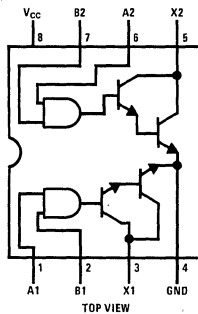
Features

- CMOS compatible inputs
- TTL compatible inputs
- High impedance inputs PNP's
- High output voltage breakdown 56V min
- High output current capability 300 mA max
- Same pin-outs and logic functions as DS75451, DS75461 and DS3611 series circuits
- Low V_{CC} power dissipation (28 mW both outputs "ON" at 5V)

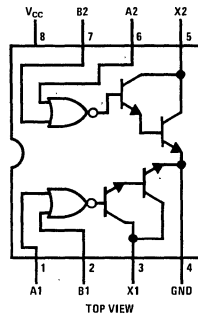
Connection Diagrams (Dual-In-Line and Metal Can Packages)



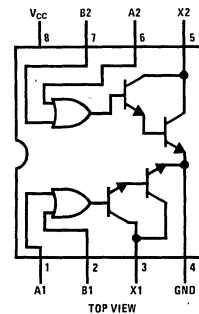
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Order Number DS1632J-8, DS3632J-8 or DS3632N

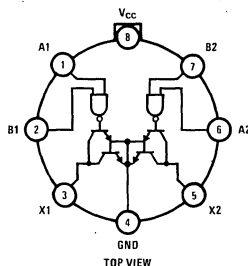


Order Number DS1633J-8, DS3633J-8 or DS3633N

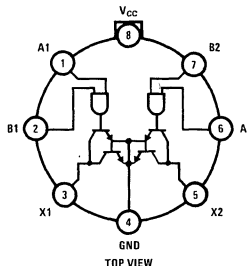


Order Number DS1634J-8, DS3634J-8 or DS3634N

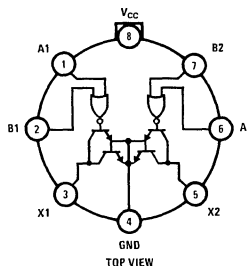
See NS Package J08A or N08A.



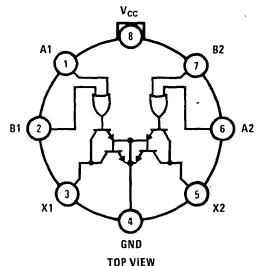
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Order Number DS1632H or DS3632H



Order Number DS1633H or DS3633H



Order Number DS1634H or DS3634H

See NS Package H08C

Absolute Maximum Ratings (Note 1)

Supply Voltage	16V
Voltage at Inputs	-0.3V to $V_{CC} + 0.3V$
Output Voltage	56V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1133 mW
Molded Package	1022 mW
TO-5 Package	787 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 7.6 mW/°C above 25°C; derate molded package 8.2 mW/°C above 25°C; derate TO-5 package 5.2 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}			
DS1631/DS1632/ DS1633/DS1634	4.5	15	V
DS3631/DS3632/ DS3633/DS3634	4.75	15	V
Temperature, T_A			
DS1631/DS1632/ DS1633/DS1634	-55	+125	°C
DS3631/DS3632/ DS3633/DS3634	0	+70	°C

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	
ALL CIRCUITS							
V_{IH}	Logical "1" Input Voltage <i>(Figure 1)</i>	$V_{CC} = 5V$	3.5	2.5		V	
		$V_{CC} = 10V$	8.0	5		V	
		$V_{CC} = 15V$	12.5	7.5		V	
V_{IL}	Logical "0" Input Voltage <i>(Figure 1)</i>	$V_{CC} = 5V$		2.5	1.5	V	
		$V_{CC} = 10V$		5.5	2.0	V	
		$V_{CC} = 15V$		7.5	2.5	V	
I_{IH}	Logical "1" Input Current	$V_{CC} = 15V, V_{IN} = 15V$, <i>(Figure 2)</i>		0.1	10	μA	
I_{IL}	Logical "0" Input Current	$V_{IN} = 0.4V$, <i>(Figure 3)</i>		-50	-120	μA	
		$V_{CC} = 15V$		-200	-360	μA	
V_{OH}	Output Breakdown Voltage	$V_{CC} = 15V, I_{OH} = 250 \mu A$, <i>(Figure 1)</i>	56	65		V	
V_{OL}	Output Low Voltage	$V_{CC} = \text{Min}$, <i>(Figure 1)</i> , DS1631, DS1632, DS1633, DS1634		0.85	1.1	V	
				1.1	1.4	V	
	$V_{CC} = \text{Min}$, <i>(Figure 1)</i> , DS3631, DS3632, DS3633, DS3634	$I_{OL} = 100 \text{ mA}$		0.85	1.0	V	
		$I_{OL} = 300 \text{ mA}$		1.1	1.3	V	
DS1631/DS3631							
$I_{CC(0)}$	Supply Currents	$V_{IN} = 0V$, <i>(Figure 4)</i>	$V_{CC} = 5V$	Output Low	7	11	mA
			$V_{CC} = 15V$	Both Drivers	14	20	mA
$I_{CC(1)}$		<i>(Figure 4)</i>	$V_{CC} = 5V, V_{IN} = 5V$	Output High	2	3	mA
			$V_{CC} = 15V, V_{IN} = 15V$	Both Drivers	7.5	10	mA
t_{PD1}	Propagation to "1"	$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 \text{ pF}, R_L = 50\Omega, V_L = 10V$, <i>(Figure 5)</i>		200		ns	
t_{PD0}	Propagation to "0"	$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 \text{ pF}, R_L = 50\Omega, V_L = 10V$, <i>(Figure 5)</i>		150		ns	
DS1632/DS3632							
$I_{CC(0)}$	Supply Currents	<i>(Figure 4)</i>	$V_{CC} = 5V, V_{IN} = 5V$	Output Low	8	12	mA
			$V_{CC} = 15V, V_{IN} = 15V$		18	23	mA
$I_{CC(1)}$		$V_{IN} = 0V$, <i>(Figure 4)</i>	$V_{CC} = 5V$	Output High	2.5	3.5	mA
			$V_{CC} = 15V$		9	14	mA
t_{PD1}	Propagation to "1"	$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 \text{ pF}, R_L = 50\Omega, V_L = 10V$, <i>(Figure 5)</i>		150		ns	
t_{PD0}	Propagation to "0"	$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 \text{ pF}, R_L = 50\Omega, V_L = 10V$, <i>(Figure 5)</i>		150		ns	
DS1633/DS3633							
$I_{CC(0)}$	Supply Currents	$V_{IN} = 0V$, <i>(Figure 4)</i>	$V_{CC} = 5V$	Output Low	7.5	12	mA
			$V_{CC} = 15V$		16	23	mA
$I_{CC(1)}$		<i>(Figure 4)</i>	$V_{CC} = 5V, V_{IN} = 5V$	Output High	2	4	mA
			$V_{CC} = 15V, V_{IN} = 15V$		7.2	15	mA
t_{PD1}	Propagation to "1"	$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 \text{ pF}, R_L = 50\Omega, V_L = 10V$, <i>(Figure 5)</i>		200		ns	
t_{PD0}	Propagation to "0"	$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 \text{ pF}, R_L = 50\Omega, V_L = 10V$, <i>(Figure 5)</i>		150		ns	

DS1631/3631, DS1632/3632,
DS1633/3633, DS1634/3634

3

Electrical Characteristics (Continued)

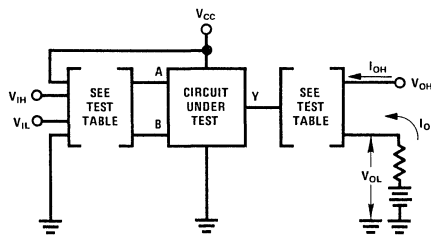
PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
DS1634/DS3634						
$I_{CC(0)}$ Supply Currents	(Figure 4)	$V_{CC} = 5V, V_{IN} = 5V$	Output Low	7.5	12	mA
		$V_{CC} = 15V, V_{IN} = 15V$		18	23	mA
$I_{CC(1)}$	$V_{IN} = 0V, (Figure 4)$	$V_{CC} = 5V$	Output High	3	5	mA
		$V_{CC} = 15V$		11	18	mA
t_{PD1} Propagation to "1"		$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 pF, R_L = 50\Omega, V_L = 10V,$ (Figure 5)		150		ns
t_{PD0} Propagation to "0"		$V_{CC} = 5V, T_A = 25^\circ C, C_L = 15 pF, R_L = 50\Omega, V_L = 10V,$ (Figure 5)		150		ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the $-55^\circ C$ to $+125^\circ C$ temperature range for the DS1631, DS1632, DS1633 and DS1634 and across the $0^\circ C$ to $+70^\circ C$ range for the DS3631, DS3632, DS3633 and DS3634. All typical values are for $T_A = 25^\circ C$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

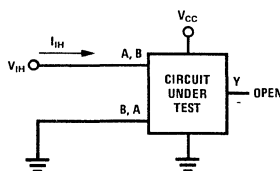
Test Circuits



CIRCUIT	INPUT UNDER TEST	OTHER INPUT	OUTPUT	
			APPLY	MEASURE
DS3631	V_{IH}	V_{IH}	I_{OH}	V_{OH}
	V_{IL}	V_{CC}	I_{OL}	V_{OL}
DS3632	V_{IH}	V_{IH}	I_{OL}	V_{OL}
	V_{IL}	V_{CC}	I_{OH}	V_{OH}
DS3633	V_{IH}	GND	I_{OH}	V_{OH}
	V_{IL}	V_{IL}	I_{OL}	V_{OL}
DS3634	V_{IH}	GND	I_{OL}	V_{OL}
	V_{IL}	V_{IL}	I_{OH}	V_{OH}

Note: Each input is tested separately.

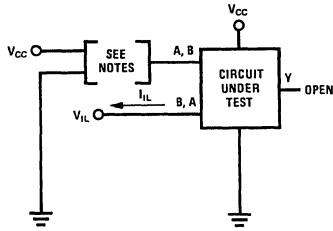
FIGURE 1. $V_{IH}, V_{IL}, V_{OH}, V_{OL}$



Each input is tested separately.

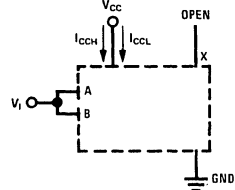
FIGURE 2. I_{IH}

Test Circuits (Continued)



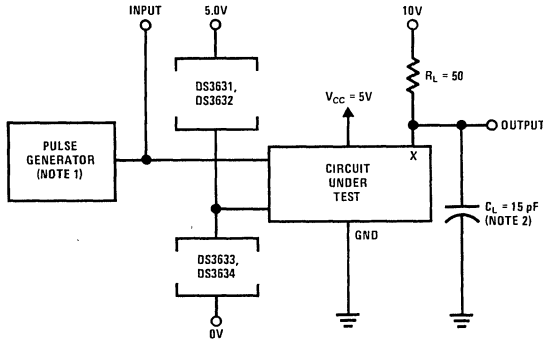
Note A: Each input is tested separately.
 Note B: When testing DS1633 and DS1634 input not under test is grounded. For all other circuits it is at V_{CC}.

FIGURE 3. I_{IL}

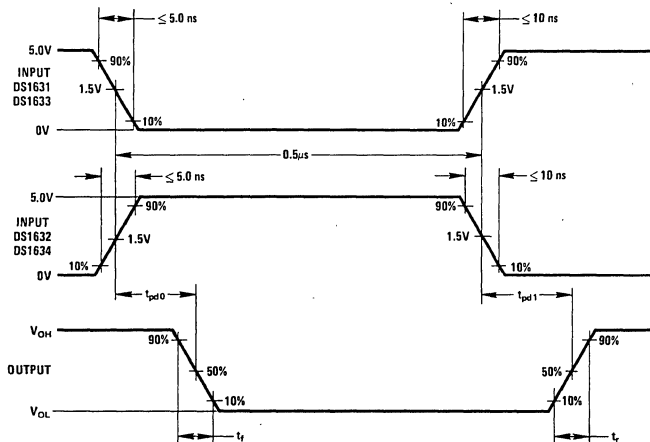


Both gates are tested simultaneously.

FIGURE 4. I_{CC}



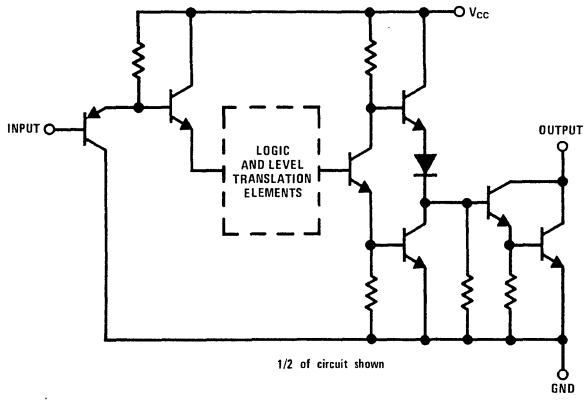
Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: PRR = 500 kHz, Z_{OUT} ≈ 50Ω.
 Note 2: C_L includes probe and jig capacitance.

FIGURE 5. Switching Times.

Schematic Diagram (Equivalent Circuit)



DS3654 Printer Solenoid Driver

General Description

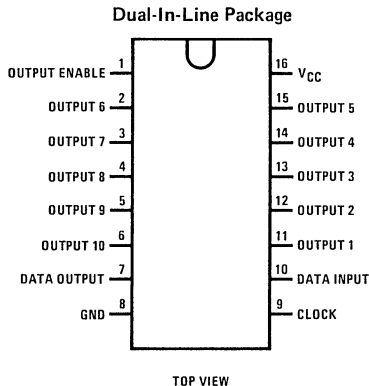
The DS3654 is a serial-to-parallel 10-bit shift register with a clock and data input, a data output from the tenth bit, and 10 open-collector clamped relay driver outputs suitable for driving printer solenoids.

Timing for the circuit is shown in *Figure 1*. Data input is sampled on the positive clock edge. Data output changes on the negative clock edge, and is always active. Enable

transfers data from the shift register to the open-collector outputs. Internal circuitry inhibits output enable for power supply voltage less than 6V.

Each output sinks 250 mA and is internally clamped to ground at 50V to dissipate energy stored in inductive loads.

Connection Diagram

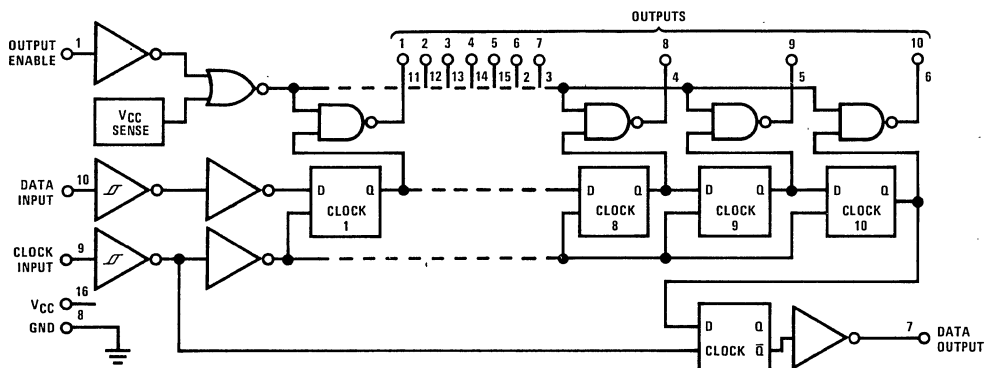


Order Number DS3654J or DS3654N
See NS Package J16A or N16A

Pin Descriptions

Pin No.	Function
1	Output Enable
2	Output 6
3	Output 7
4	Output 8
5	Output 9
6	Output 10
7	Data Output
8	Ground
9	Clock Input
10	Data Input
11	Output 1
12	Output 2
13	Output 3
14	Output 4
15	Output 5
16	VCC

Logic Diagram



Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	9.5V max
Input Voltage	-0.5V min, 9.5V max
Output Supply, V_{p-p}	±45V max
Storage Temperature Range	-65°C to +150°C
Output Current (Single Output)	0.4A
Ground Current	4.0A
Peak Power Dissipation, $t < 10$ ms, Duty Cycle < 5%	4.5W Max
Maximum Power Dissipation* at 25°C	
Cavity Package	1635 mW
Molded Package	1687 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.9 mW/°C above 25°C; derate molded package 13.5 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	7.5	9.5	V
Temperature (T_A)	0	+70	°C
Output Supply (V_{p-p})		40	V

Electrical Characteristics (Notes 2, 3 and 4) $V_{p-p} = 30V$ unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Logical "1" Input Voltage		2.6			V
Logical "0" Input Voltage				0.8	V
Logical "1" Output Voltage Clamp	$I_{CLAMP} = 0.1A, V_{EN} = 0V$	45	50	65	V
Logical "1" Output Current	$V_{OH} = 40V, V_{EN} = 0$			1.0	mA
Logical "0" Output Voltage	$I_{OL} = 250$ mA, $V_{EN} = 2.6V$			1.6	V
Logical "1" Input Current					
Clock	$T_A = 70^\circ C, V_{CL} = 2.6V$	0.2	0.33		mA
Enable	$T_A = 70^\circ C, V_{EN} = 2.6V$	0.2	0.33		mA
Data	$T_A = 70^\circ C, V_D = 2.6V$	0.3	0.57		mA
Clock	$T_A = 0^\circ C, V_{CL} = 2.6V$		0.33	0.5	mA
Enable	$T_A = 0^\circ C, V_{EN} = 2.6V$		0.33	0.5	mA
Data	$T_A = 0^\circ C, V_D = 2.6V$		0.57	0.75	mA
Logical "0" Input Current					
Clock	$T_A = 70^\circ C, V_{CL} = 1V$		125		μA
Enable	$T_A = 70^\circ C, V_{EN} = 1V$		125		μA
Data	$T_A = 70^\circ C, V_D = 1V$		220		μA
Input Pull-Down Resistance					
Clock	$T_A = 25^\circ C, V_{CL} < V_{CC}$		8		kΩ
Enable	$T_A = 25^\circ C, V_{EN} < V_{CC}$		8		kΩ
Data	$T_A = 25^\circ C, V_D < V_{CC}$		4.5		kΩ
Supply Current (I_{CC})					
Outputs Disabled	$T_A \geq 25^\circ C, V_{EN} = 0, V_{DO} = 0,$ $V_{CC} = 9.5V$		27	40	mA
Outputs Enabled	$T_A \geq 25^\circ C, V_{EN} = 2.6, I_{OL} = 250$ mA Each Bit		55	70	mA
Data Output Low (V_{DOL})	$V_D = 0, I_{OL} = 0$		0.01	0.5	V
Data Output High (V_{DOH})	$V_D = 2.6, I_{OH} = -0.75$ mA	2.6	3.4		V
Data Output Pull-Down Resistance	$V_D = 0, V_{DO} = 1V$		14		kΩ

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C temperature range and the 7.5V to 9.5V power supply range. All typical values given are for $V_{CC} = 8.5V$ and $T_A = 25^\circ C$.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

Switching Characteristics 0°C to +70°C, T_A = 25°C, nominal power supplies unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
Clk, Data and Enable Inputs	(Figure 1)				
t _{FC}				2.0	μs
t _{RC}	t _{BIT} ≥ 10 μs			2.0	μs
t _{CLK}		2			μs
t _{CLK}		3.5			μs
t _{HOLD}				1.0	μs
t _{SET-UP}				1.0	μs
t _{RE} , t _{RD IN}				1.0	μs
t _{FE} , t _{FD IN}				5.0	μs
Output 1–10	V _{p-p} = 20V				
t _{RO}	R _L = 100Ω, C _L < 100 pF		1.2		μs
t _{FO}	R _L = 100Ω, C _L < 100 pF		1.2		μs
t _{PDEH}			3.5		μs
t _{PDEL}			3.0		μs
Data Output	R _L = 5 kΩ, C _L ≤ 10 pF				
t _{PDH} , t _{PDL}			0.8	2.5	μs
t _{RD}			0.4		μs
t _{FD}			0.4		μs
Clock to Enable Delay					
t _{CE}		2 t _{BIT}			μs
Enable to Clock Delay		t _{BIT}			μs

Switching Time Waveforms

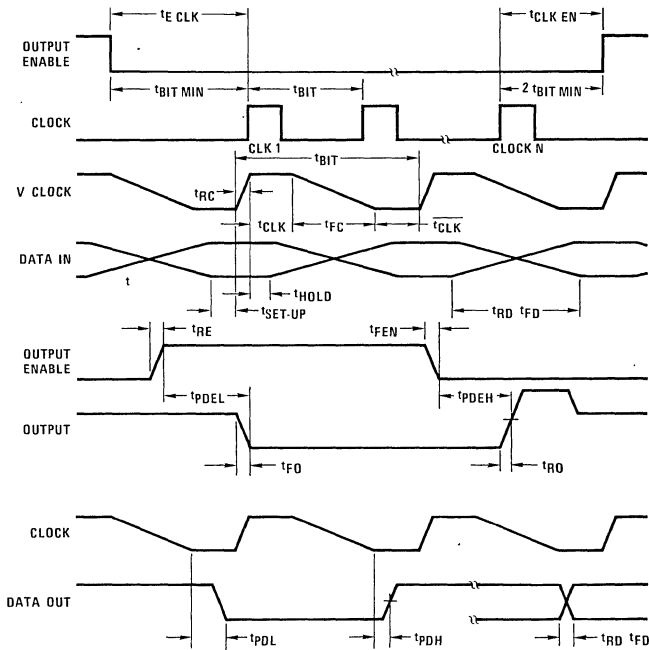


FIGURE 1. Shift Timing

Definition of Terms

V_{p-p}: Output power supply voltage. The return for open-collector relay driver outputs.

t_{BIT}: Period of the incoming clock.

V_{CLK}: The voltage at the clock input.

t_{CLK}: The portion of t_{BIT} when $V_{CLK} \geq 2.6V$.

t_{CLK}: The portion of t_{BIT} when $V_{CLK} \leq 0.8V$

t_{SET-UP}: The time prior to the end of t_{CLK} required to insure valid data at the shift register input for subsequent clock transitions.

t_{HOLD}: The time following the start of t_{CLK} required to transfer data within the shift register.

DS3656 Quad Peripheral Driver

General Description

The DS3656 is a quad peripheral driver designed for use in automotive applications. Logically it is an open collector NAND function with all inputs compatible with 74LS and CMOS series products. An enable input is provided that is common to each driver. When taken to a logic zero level all outputs will turn off. Also, overvoltage is detected.

The DS3656 has features associated with the output structure that make it highly versatile to many applications. Each output is capable of 600 mA sink currents and offers 65V standoff voltage in non-inductive applications. A clamp network capable of handling 800 mA is incorporated in each output which eliminates the need of an external network to quench the high voltage backswing caused when switching inductive loads up to 30V (reference AN-213).

The DS3656 is intended to operate from a 12V automotive battery. Internal to the device is its own voltage regulator which permits the device to operate during the wide voltage variation seen in many automotive applications. An overvoltage-protection circuit is incorporated that will cause the outputs to turn off when the supply exceeds 30V. The circuit is designed to withstand worst case fault conditions that occur in automotive applications, such as

high voltage transients and reverse battery connection. In this type of environment an external 100Ω resistor must be connected in series with the V_{CC} line.

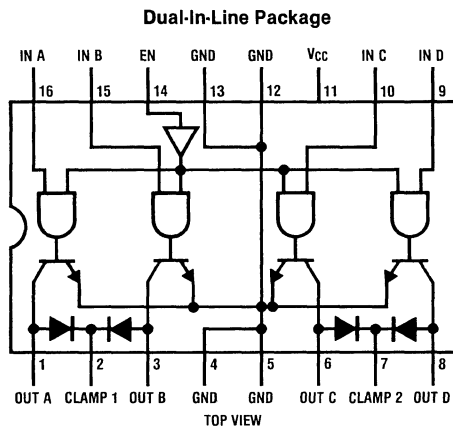
The molded package is specifically constructed to allow increased power dissipation over conventional packages. The four ground pins are directly connected to the device chip with a special copper lead frame. When the quad driver is soldered into a copper PC board the power rating of the device will significantly improve.

Features

- Quad automotive peripheral driver
- 600 mA output current capability
- High voltage outputs — 65V
- Clamp diode provided for inductive loads
- Built in regulator
- Overvoltage failsafe
- TTL/LS/CMOS compatible diode clamped inputs
- High power dissipation package
- Guaranteed to withstand worst case fault conditions

3

Connection Diagram



Order Number DS3656N
See NS Package N16A

Truth Table

Enable	In X	Out X
H	H	L
H	L	H
L	X	H

H = high level L = low level X = irrelevant

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC} (Note 2)	65V
Input Voltage	7V
Output Voltage	65V
Continuous Output Current	1.2A
Junction Temperature	150°C
Thermal Resistance (Junction to Ambient)	
DS3656N Plugged in a Socket	60°C/W
DS3656N Soldered in a PC Board	35°C/W
DS3656N Soldered in a PC Board with 6 in ² Cu Foil	20°C/W
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage, V_{CC}	10.5	17.0	V
Temperature	-40	105	°C

Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Max	Units
V_{CC}	Power Supply Voltage		10.5	17	V
I_{CC}	Power Supply Current			65	mA
V_{IH}	High Level Input Voltage		2.0		V
V_{IL}	Low Level Input Voltage			0.8	V
I_{IH}	High Level Input Current	$V_{IN} = 2.7V$		20	μA
I_{IL}	Low Level Input Current	$V_{IN} = 0.4V$		-360	μA
V_{ICL}	Input Clamp Voltage	$I_{IN} = -10\text{ mA}$		-1.5	V
V_{OL}	Low Level Output Voltage	$I_L = 600\text{ mA}, V_{CC} = 10.5V$		1.5	V
I_{OH}	High Level Leakage Current	$V_{OH} = 65V$		1.0	mA
V_F	Output Diode Forward Voltage	$I_F = 800\text{ mA}$		2.5	V
I_R	Output Diode Reverse Leakage	$V_R = 65V$		1.0	mA
B_{VCER}	V_{OH1} Switching Capacitive or Resistive Load			65	V
L_{VCEO}	V_{OH2} Switching Inductive Clamped Load			30	V

Switching Characteristics $V_{CC} = 13.2V, T_A = 25^\circ C$

Symbol	Parameter	Conditions	Min	Max	Units
t_{PLH}	Propagation Delay Time Low to High Level Output	$V_{CC} = 13.2V, R_L = 30\Omega, C_L = 15\text{ pF}$		10	μs
t_{PHL}	Propagation Delay Time High to Low Level Output	$V_{CC} = 13.2V, R_L = 30\Omega, C_L = 15\text{ pF}$		10	μs
t_{TLH}	Transition Time Low to High Level Output	$V_{CC} = 13.2V, R_L = 30\Omega, C_L = 15\text{ pF}$		500	ns
t_{THL}	Transition Time High to Low Level Output	$V_{CC} = 13.2V, R_L = 30\Omega, C_L = 15\text{ pF}$		500	ns
t_{PLH}	Enable to Output	$V_{CC} = 13.2V, R_L = 30\Omega, C_L = 15\text{ pF}$		10	μs
t_{PHL}	Enable to Output	$V_{CC} = 13.2V, R_L = 30\Omega, C_L = 15\text{ pF}$		10	μs

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Voltage values are with respect to network ground terminal unless otherwise specified.

Note 3: Unless otherwise specified min/max limits apply across the -40°C to +105°C temperature range.

DS3658 Quad High Current Peripheral Driver

General Description

The DS3658 quad peripheral driver is designed for those applications where low operating power, high breakdown voltage, high output current and low output ON voltage are required. A unique input circuit combines TTL compatibility with high impedance. In fact, its extreme low input current allows it to be driven directly by a CMOS device.

The outputs are capable of sinking 600 mA each and offer a 70V breakdown. However, for inductive loads the output should be clamped to 35V or less to avoid latch-up during turn off (inductive fly back protection—refer AN-213). An on-chip clamp diode capable of handling 800 mA is provided at each output for this purpose. In addition, the DS3658 incorporates circuitry that guarantees glitch-free power up or down operation and a fail-safe feature which puts the output in a high impedance state when input is open.

The molded package is specifically constructed to allow increased power dissipation over conventional packages. The four ground pins are directly connected to the device chip with a special copper lead frame. When the quad driver is soldered into a PC board, the power rating of the device improves significantly.

Applications

- Relay drivers
- Lamp drivers
- Solenoid drivers
- Hammer drivers
- Stepping motor drivers
- Triac drivers

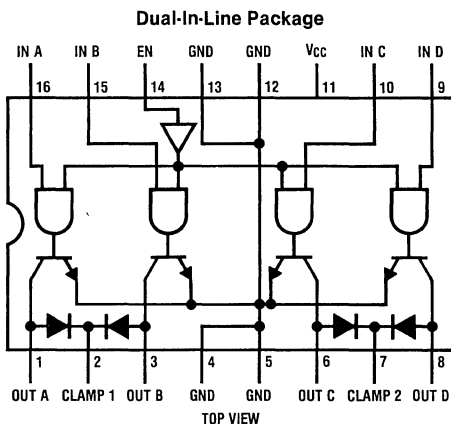
- LED drivers
- High current, high voltage drivers
- Level translators
- Fiber optic LED drivers

Features

- Single saturated transistor outputs
- Low standby power, 10 mW typical
- High impedance TTL compatible inputs
- Outputs may be tied together for increased current capacity
- High output current
600 mA per output
2.4A per package
- No output latch-up at 35V
- Low output ON voltage (350 mV typ @ 600 mA)
- High breakdown voltage (70V)
- Open collector outputs
- Output clamp diodes for inductive fly back protection
- NPN inputs for minimal input currents (1 μ A typical)
- Low operating power
- Standard 5V power supply
- Power up/down protection
- Fail safe operation
- 2W power package
- Pin-for-pin compatible with SN75437

3

Connection Diagram



Truth Table

IN	EN	OUT
H	H	L
L	H	Z
H	L	Z
L	L	Z

H = High state
L = Low state
Z = High impedance state

Order Number DS3658N
See NS Package N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Input Voltage	15V
Output Voltage	70V
Output Current	1.5A
Continuous Power Dissipation @ 25°C Free-Air (Note 5)	2075 mW
Storage Temperature Range	- 65°C to + 150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage	4.75	5.25	V
Ambient Temperature	0	70	°C

Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V _{IH}	Input High Voltage		2.0			V
V _{IL}	Input Low Voltage				0.8	V
I _{IH}	Input High Current	V _{IN} = 5.25V, V _{CC} = 5.25V		1.0	10	μA
I _{IL}	Input Low Current	V _{IN} = 0.4V			± 10	μA
V _{IK}	Input Clamp Voltage	I _I = - 12 mA		- 0.8	- 1.5	V
V _{OL}	Output Low Voltage	I _L = 300 mA		0.2	0.4	V
		I _L = 600 mA (Note 4)		0.35	0.7	V
I _{CEX}	Output Leakage Current	V _{CE} = 70V, V _{IN} = 0.8V			100	μA
V _F	Diode Forward Voltage	I _F = 800 mA		1.0	1.6	V
I _R	Diode Leakage Current	V _R = 70V			100	μA
I _{CC}	Supply Current	All Inputs High		50	65	mA
		All Inputs Low		2	4	mA

Switching Characteristics (Note 2)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t _{HL}	Turn On Delay	R _L = 60Ω, V _L = 30V		226	500	ns
t _{LH}	Turn Off Delay	R _L = 60Ω, V _L = 30V		2430	8000	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

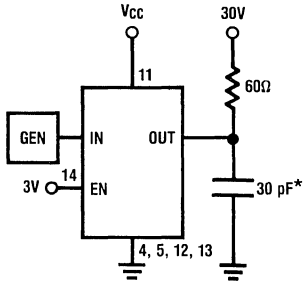
Note 2: Unless otherwise specified, min/max limits apply across the 0°C to + 70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for T_A = 25°C and V_{CC} = 5.0V.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max or min are so classified on absolute value basis.

Note 4: All sections of this quad circuit may conduct rated current simultaneously; however, power dissipation averaged over a short interval of time must fall within specified continuous dissipation ratings.

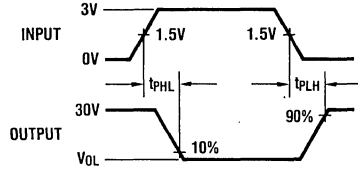
Note 5: For operation over 25°C free-air temperature, derate linearly to 1328 mW @ 70°C @ the rate of 16.6 mW/°C.

AC Test Circuit



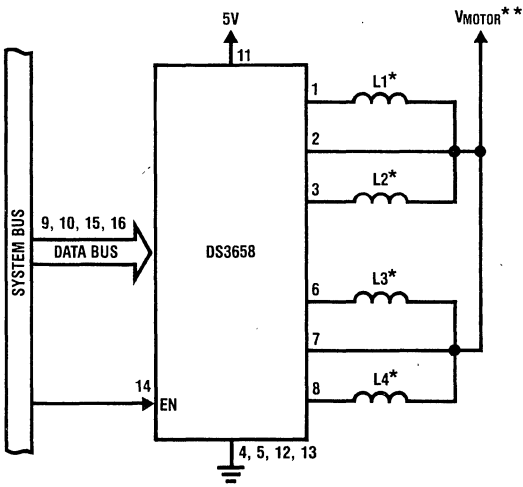
*Includes probe and jig capacitance

Switching Waveforms

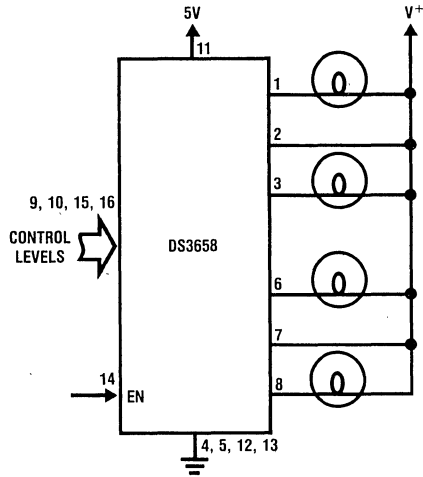


Typical Applications

Stepping Motor Driver



Lamp Driver



* L1, L2, L3, L4 are the windings of a bifilar stepping motor.

** VMOTOR is the supply voltage of the motor.

DS3668 Quad Fault Protected Peripheral Driver

General Description

The DS3668 quad peripheral driver is designed for those applications where low operating power, high breakdown voltage, high output current and low output ON voltage are required. Unlike most peripheral drivers available, a unique fault protection circuit is incorporated on each output. When the load current exceeds 1.0 A (approximately) on any output for more than a built-in delay time, nominally 25 μ s, that output will be shut off by its protection circuitry with no effect on other outputs. This condition will prevail until that protection circuitry is reset by toggling the corresponding input or the enable pin low for at least 0.5 μ s. The 25 μ s built-in delay is provided to ensure that the protection circuitry is not triggered by turn-on surge currents associated with certain kinds of loads.

The DS3668's inputs combine TTL compatibility with high input impedance. In fact, its extreme low input current allows it to be driven directly by a MOS device. The outputs are capable of sinking 600 mA each and offer a 70V breakdown. However, for inductive loads the output should be clamped to 35V or less to avoid latch up during turn off (inductive fly-back protection — refer AN-213). An on-chip clamp diode capable of handling 800 mA is provided at each output for this purpose. In addition, the DS3668 incorporates circuitry that guarantees glitch-free power up or down operation and a fail-safe feature which puts the output in a high impedance state when the input is open.

The molded package is specifically constructed to allow increased power dissipation over conventional packages. The four ground pins are directly connected to the device chip with a special copper lead frame. When the quad driver is soldered into a PC board, the power rating of the device improves significantly.

Applications

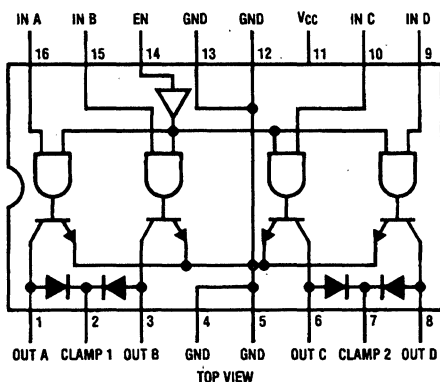
- Relay drivers
- Solenoid drivers
- Hammer drivers
- Stepping motor drivers
- Triac drivers
- LED drivers
- High current, high voltage drivers
- Level translators
- Fiber optic LED drivers

Features

- Output fault protection
- High impedance TTL compatible inputs
- High output current — 600 mA per output
- No output latch-up at 35V
- Low output ON voltage (550 mV typ @ 600 mA)
- High breakdown voltage (70V)
- Open collector outputs
- Output clamp diodes for inductive fly-back protection
- NPN inputs for minimal input currents (1 μ A typical)
- Low operating power
- Standard 5V power supply
- Power up/down protection
- Fail-safe operation
- 2W power package
- Pin-for-pin compatible with SN75437

Connection Diagram *

Dual-In-Line Package



Truth Table

IN	EN	OUT
H	H	L
L	H	Z
H	L	Z
L	L	Z

H = High state
 L = Low state
 Z = High impedance state

Order Number DS3668N
 See NS Package N16A

* See Page 3 for the detail of output protection.

Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Input Voltage	15V
Output Voltage	70V
Continuous Power Dissipation @25°C Free-Air (Note 5)	2075 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage	4.75	5.25	V
Ambient Temperature	0	70	°C

Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	Input High Voltage		2.0			V
V_{IL}	Input Low Voltage				0.8	V
I_{IH}	Input High Current	$V_{IN} = 5.25V, V_{CC} = 5.25V$		1.0	20	μA
I_{IL}	Input Low Current	$V_{IN} = 0.4V$			± 10	μA
V_{IK}	Input Clamp Voltage	$I_I = -12 \text{ mA}$		-0.8	-1.5	V
V_{OL}	Output Low Voltage	$I_L = 300 \text{ mA}$		0.2	0.7	V
		$I_L = 600 \text{ mA}$ (Note 4)		0.55	1.5	V
I_{CEX}	Output Leakage Current	$V_{CE} = 70V, V_{IN} = 0.8V$			100	μA
V_F	Diode Forward Voltage	$I_F = 800 \text{ mA}$		1.2		V
I_R	Diode Leakage Current	$V_R = 70V$			100	μA
I_{CC}	Supply Current	All Inputs High		62	80	mA
		All Inputs Low		20		mA
I_{TH}	Protection Circuit Threshold Current			1		A

Switching Characteristics (Note 2)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{HL}	Turn On Delay	$R_L = 60\Omega, V_L = 30V$		300		ns
t_{LH}	Turn Off Delay	$R_L = 60\Omega, V_L = 30V$		2000		ns
t_{FZ}	Protection Enable Delay (after Detection of fault)			25		μs
t_{RL}	Input Low Time For Protection Circuit Reset		1.0			μs

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

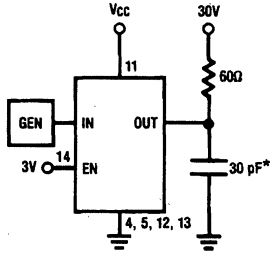
Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0V$.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max or min are so classified on absolute value basis.

Note 4: All sections of this quad circuit may conduct rated current simultaneously; however, power dissipation averaged over a short interval of time must fall within specified continuous dissipation ratings.

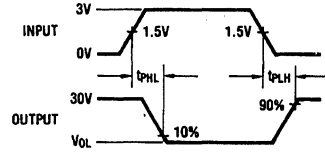
Note 5: For operation over 25°C free-air temperature, derate linearly to 1328 mW @ 70°C @ the rate of 16.6 mW/°C.

AC Test Circuit



TL/F/5225-2

Switching Waveforms

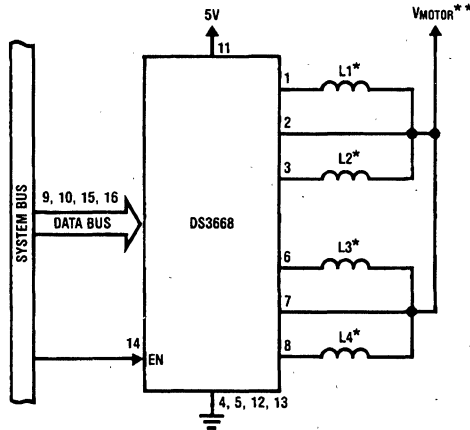


TL/F/5225-3

*Includes probe and jig capacitance

Typical Application

Stepping Motor Driver

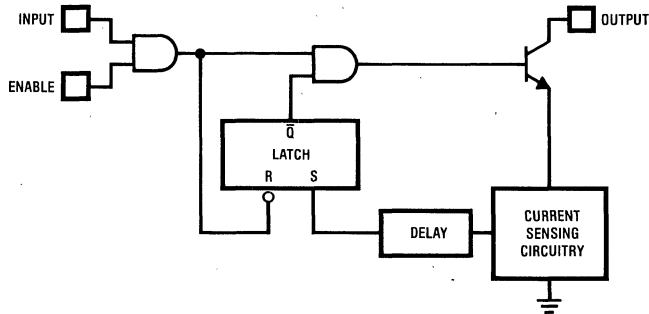


TL/F/5225-4

*L1, L2, L3, L4 are the windings of a bifilar stepping motor.

**VMOTOR is the supply voltage of the motor.

Protection Circuit Block Diagram



TL/F/5225-5

DS3669 Quad High Current Peripheral Driver

General Description

The DS3669 is a non-inverting quad peripheral driver similar to the DS3658. These drivers are designed for those applications where low operating power, high breakdown voltage, high output current and low output ON voltage are required. A unique input circuit combines TTL compatibility with high impedance. In fact, its extreme low input current allows it to be driven directly by a CMOS device.

The outputs are capable of sinking 600 mA each and offer a 70V breakdown. However, for inductive loads the output should be clamped to 35V or less to avoid latch-up during turn off (inductive fly back protection—refer AN-213). An on-chip clamp diode capable of handling 800 mA is provided at each output for this purpose. In addition, the DS3669 incorporates circuitry that guarantees glitch-free power up or down operation.

The molded package is specifically constructed to allow increased power dissipation over conventional packages. The four ground pins are directly connected to the device chip with a special copper lead frame. When the quad driver is soldered into a PC board, the power rating of the device improves significantly.

Applications

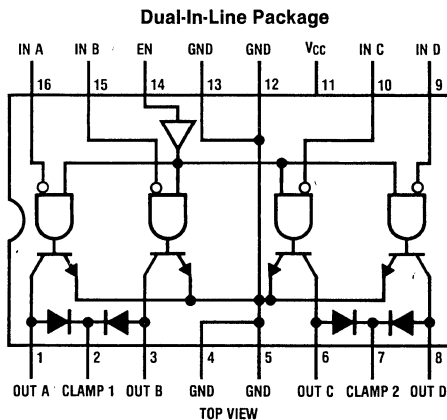
- Relay drivers
- Lamp drivers
- Solenoid drivers
- Hammer drivers

- Stepping motor drivers
- Triac drivers
- LED drivers
- High current, high voltage drivers
- Level translators
- Fiber optic LED drivers

Features

- Single saturated transistor outputs
- Low standby power, 10 mW typical
- High impedance TTL compatible inputs
- Outputs may be tied together for increased current capacity
- High output current
600 mA per output
2.4A per package
- No output latch-up at 35V
- Low output ON voltage (350 mV typ @ 600 mA)
- High breakdown voltage (70V)
- Open collector outputs
- Output clamp diodes for inductive fly back protection
- NPN inputs for minimal input currents (1 μ A typical)
- Low operating power
- Standard 5V power supply
- Power up/down protection
- 2W power package

Connection Diagram



Order Number DS3669N
See NS Package N16A

Truth Table

IN	EN	OUT
L	H	L
H	H	Z
L	L	Z
H	L	Z

H = High state
L = Low state
Z = High Impedance state

Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Input Voltage	15V
Output Voltage	70V
Output Current	1.5A
Continuous Power Dissipation @ 25°C Free-Air (Note 5)	2075 mW
Storage Temperature Range	- 65°C to + 150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage	4.75	5.25	V
Ambient Temperature	0	70	°C

Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	Input High Voltage		2.0			V
V_{IL}	Input Low Voltage				0.8	V
I_{IH}	Input High Current	$V_{IN} = 5.25V, V_{CC} = 5.25V$		1.0	10	μA
I_{IL}	Input Low Current	$V_{IN} = 0.4V$			± 10	μA
V_{IK}	Input Clamp Voltage	$I_I = -12 \text{ mA}$		-0.8	-1.5	V
V_{OL}	Output Low Voltage	$I_L = 300 \text{ mA}$		0.2	0.4	V
		$I_L = 600 \text{ mA}$ (Note 4)		0.35	0.7	V
I_{CEX}	Output Leakage Current	$V_{CE} = 70V, V_{IN} = 2V,$ $V_{EN} = 0.8V$			100	μA
V_F	Diode Forward Voltage	$I_F = 800 \text{ mA}$		1.0	1.6	V
I_R	Diode Leakage Current	$V_R = 70V$			100	μA
I_{CC}	Supply Current	All Inputs Low $EN = 2.0V$		50	65	mA
		All Inputs High		2	4	mA

Switching Characteristics (Note 2)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{HL}	Turn On Delay	$R_L = 60\Omega, V_L = 30V$		226	500	ns
t_{LH}	Turn Off Delay	$R_L = 60\Omega, V_L = 30V$		2430	8000	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25^\circ C$ and $V_{CC} = 5.0V$.

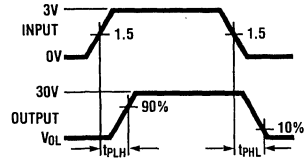
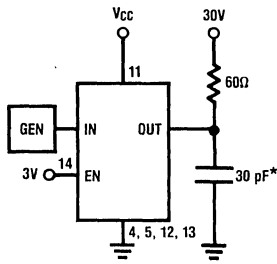
Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max or min are so classified on absolute value basis.

Note 4: All sections of this quad circuit may conduct rated current simultaneously; however, power dissipation averaged over a short interval of time must fall within specified continuous dissipation ratings.

Note 5: For operation over 25°C free-air temperature, derate linearly to 1328 mW @ 70°C @ the rate of 16.6 mW/°C.

AC Test Circuit

Switching Waveforms

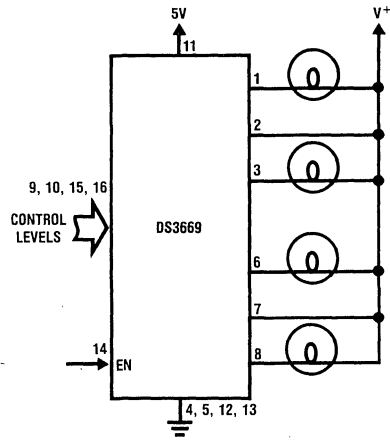
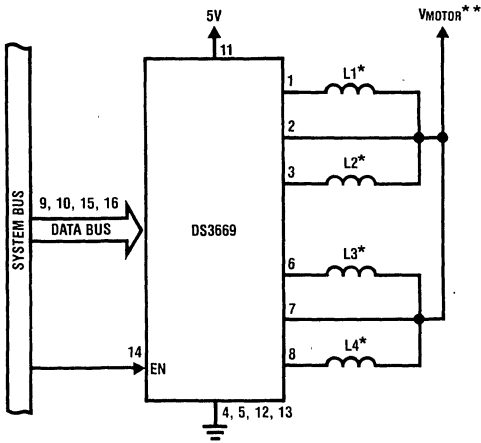


*Includes probe and jig capacitance

Typical Applications

Stepping Motor Driver

Lamp Driver



* L1, L2, L3, L4 are the windings of a bifilar stepping motor.

** VMOTOR is the supply voltage of the motor.

DS3680 Quad Negative Voltage Relay Driver

General Description

The DS3680 is a quad high voltage negative relay driver designed to operate over wide ranges of supply voltage, common-mode voltage, and ambient temperature, with 50 mA sink capability. These drivers are intended for switching the ground end of loads which are directly connected to the negative supply, such as in telephone relay systems.

Since there may be considerable noise and IR drop between logic ground and negative supply ground in many applications, these drivers are designed to operate with a high common-mode range ($\pm 20V$ referenced to negative supply ground). Each driver has a common-mode range separate from the other drivers in the package, which permits input signals from more than one element of the system.

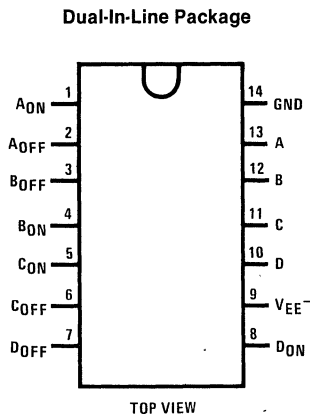
With low differential input current requirements (typically $100 \mu A$), these drivers are compatible with TTL, LS and CMOS logic. Differential inputs permit either inverting or non-inverting operation.

The driver outputs incorporate transient suppression clamp networks, which eliminate the need for external clamp networks when used in applications of switching inductive loads. A fail-safe feature is incorporated to insure that, if the V_{ON} input or both inputs are open, the driver will be OFF.

Features

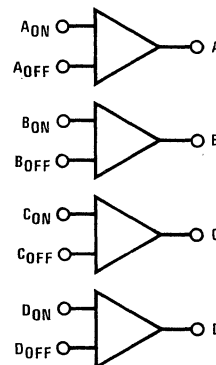
- $-10V$ to $-60V$ operation
- Quad 50 mA sink capability
- TTL/LS/CMOS or voltage comparator input
- High input common-mode voltage range
- Very low input current
- Fail-safe disconnect feature
- Built-in output clamp diode

Connection Diagram



Order Number DS3680J or DS3680N
See NS Package J14A or N14A

Logic Diagram



Absolute Maximum Ratings (Note 1)

Supply Voltage: GND to V_{EE}^- , and Any Pin	-70V
Positive Input Voltage: Input to GND	20V
Negative Input Voltage: Input to V_{EE}^-	-5V
Differential Input Voltage: V_{ON} to V_{OFF}	$\pm 20V$
Inductive Load	$L_L \leq 5h$ $I_L \leq 50\text{ mA}$
Output Current	-100 mA
Storage Temperature	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1398 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 11.2 mW/°C above 25°C.

Recommended Operating Conditions

	Min	Max	Units
Supply Voltage: GND to V_{EE}^-	-10	-60	V
Input Voltage: Input to GND	-20	20	V
Logic ON Voltage: V_{ON} Referenced to V_{OFF}	2	20	V
Logic OFF Voltage: V_{ON} Referenced to V_{OFF}	-20	0.8	V
Temperature Range	-25	85	°C

Electrical Characteristics (Notes 2 and 3)

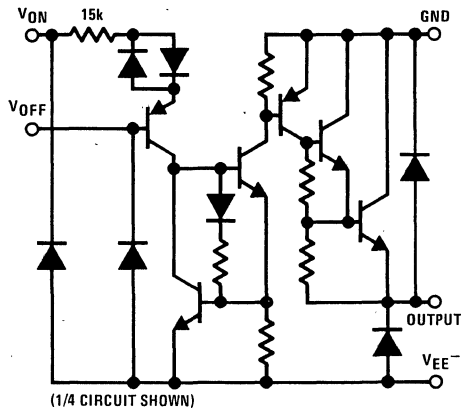
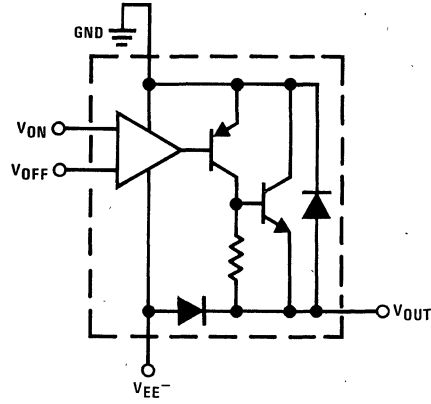
Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	Logic "1" Input Voltage	2.0	1.3		V
V_{IL}	Logic "0" Input Voltage		1.3	0.8	V
I_{INH}	Logic "1" Input Current	$V_{IN} = 2V$	40	100	μA
		$V_{IN} = 7V$	375	1000	μA
I_{INL}	Logic "0" Input Current	$V_{IN} = 0.4V$	-0.01	-5	μA
		$V_{IN} = -7V$	-1	-100	μA
V_{OL}	Output ON Voltage	$I_{OL} = 50\text{ mA}$	-1.6	-2.1	V
I_{OFF}	Output Leakage	$V_{OUT} = V_{EE}^-$	-2	-100	μA
I_{FS}	Fail-Safe Output Leakage	$V_{OUT} = V_{EE}^-$ (Inputs Open)	-2	-100	μA
I_{LC}	Output Clamp Leakage Current	$V_{OUT} = GND$	2	100	μA
V_C	Output Clamp Voltage	$I_{CLAMP} = -50\text{ mA}$ Referenced to V_{EE}^-	-2	-1.2	V
V_P	Positive Output Clamp Voltage	$I_{CLAMP} = 50\text{ mA}$ Referenced to GND	0.9	1.2	V
$I_{EE(ON)}$	ON Supply Current	All Drivers ON	-2	-4.4	mA
$I_{EE(OFF)}$	OFF Supply Current	All Drivers OFF	-1	-100	μA
$t_{PD(ON)}$	Propagation Delay to Driver ON	$L = 1h, R_L = 1k,$ $V_{IN} = 3V$ Pulse	1	10	μs
$t_{PD(OFF)}$	Propagation Delay to Driver OFF	$L = 1h, R_L = 1k,$ $V_{IN} = 3V$ Pulse	1	10	μs

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range", they are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, the min/max limits of the table of "Electrical Characteristics" apply within the range of the table of "Operating Conditions". All typical values are given for $V_{EE}^- = 52V$, and $T_A = 25^\circ C$.

Note 3: All current into device pins shown as positive, out of the device as negative. All voltages are referenced to ground unless otherwise noted.

Schematic Diagrams



DS3686 Dual Positive Voltage Relay Driver

General Description

The DS3686 is a high voltage/current positive voltage relay driver having many features not available in present relay drivers.

PNP inputs provide both TTL/LS compatibility and high input impedance for low input loading.

Output leakage is specified over temperature at an output voltage of 54V. Minimum output breakdown (ac/latch breakdown) is specified over temperature at 5 mA. This clearly defines the actual breakdown of the device since the circuit has incorporated in it an internal reference which does not allow output breakdown latching found in existing relay drivers. Additionally, this internal reference circuit feature will eliminate the need in most cases of an external clamping (inductive transient voltage protection) diode. When the output is turned "OFF" by input logic conditions the resulting inductive voltage transient seen at the output is detected by an internal zener reference. The reference then momentarily activates the output transistor long enough so that the relay energy is discharged. This feature eliminates the need of external circuit protection components and insures output transistor protection.

The outputs are Darlington connected transistors, which allow high current operation at low internal V_{CC}

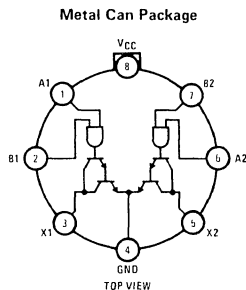
current levels—base drive for the output transistor is obtained from the load in proportion to the required loading conditions. Typical V_{CC} power with both outputs "ON" is 90 mW.

The circuit also features output transistor protection if the V_{CC} supply is lost by forcing the output into the high impedance "OFF" state with the same breakdown levels as when V_{CC} was applied.

Features

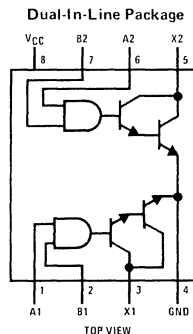
- TTL/LS/CMOS compatible inputs
- High impedance inputs (PNP's)
- High output voltage breakdown (65V typ)
- High output current capability (300 mA max)
- Internal protection circuit eliminates need for output protection diode
- Output breakdown protection if V_{CC} supply is lost
- Low V_{CC} power dissipation (90 mW (typ) both outputs "ON")
- Voltage and current levels compatible for use in telephone relay applications

Connection Diagrams



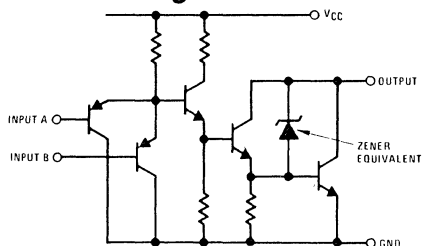
Pin 4 is in electrical contact with the case

Order Number DS3686H
See NS Package H08C



Order Number DS3686J-8 or DS3686N
See NS Package J08A or N08A

Schematic Diagram



Truth Table

Positive logic: $\overline{AB} = X$

A	B	OUTPUT X
0	0	1
1	0	1
0	1	1
1	1	0

Logic "0" output "ON"
Logic "1" output "OFF"

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	15V
Output Voltage	56V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1133 mW
Molded Package	1022 mW
TO-5 Package	787 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 7.6 mW/°C above 25°C; derate molded package 8.2 mW/°C above 25°C; derate TO-5 package 5.2 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}	4.75	5.25	V
Temperature, T_A	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

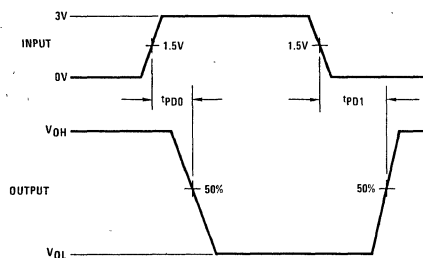
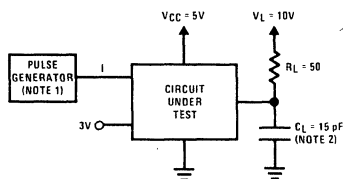
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V_{IH}	Logical "1" Input Voltage	$R_L = 180\Omega, V_L = 54V, V_O \leq 2.5V$		2.0	V	
I_{IH}	Logical "1" Input Current	$V_{CC} = \text{Max}, V_{IN} = 5.5V$		0.01	40 μA	
V_{IL}	Logical "0" Input Voltage	$R_L = 180\Omega, V_L = 54V, V_O \leq 53.8V$		0.8	V	
I_{IL}	Logical "0" Input Current	$V_{CC} = \text{Max}, V_{IN} = 0.4V$		-150	-250 μA	
V_{CD}	Input Clamp Voltage	$V_{CC} = 5V, I_{CLAMP} = -12 \text{ mA}, T_A = 25^\circ\text{C}$		-1.0	-1.5 V	
V_{OH}	Output Breakdown	$V_{CC} = \text{Max}, V_{IN} = 0V, I_{OUT} = 5 \text{ mA}$		56	65 V	
I_{OH}	Output Leakage	$V_{CC} = \text{Max}, V_{IN} = 0.4V, V_{OUT} = 54V$		0.5	250 μA	
V_{OL}	Output ON Voltage	$V_{CC} = \text{Min}, V_{IN} = 2.4V$	DS3668	$I_{OL} = 100 \text{ mA}$	0.85	1.0 V
				$I_{OL} = 300 \text{ mA}$	1.0	1.2 V
$I_{CC(1)}$	Supply Current (Both Drivers)	$V_{CC} = \text{Max}, V_{IN} = 0V, \text{Outputs Open}$		2	4 mA	
$I_{CC(0)}$	Supply Current (Both Drivers)	$V_{CC} = \text{Max}, V_{IN} = 3V, \text{Outputs Open}$		18	28 mA	
t_{PD0}	Propagation Delay to a Logical "0" (Output Turn ON)	$C_L = 15 \text{ pF}, V_L = 10V, R_L = 50\Omega, T_A = 25^\circ\text{C}, V_{CC} = 5V$		50	ns	
t_{PD1}	Propagation Delay to a Logical "1" (Output Turn OFF)	$C_L = 15 \text{ pF}, V_L = 10V, R_L = 50\Omega, T_A = 25^\circ\text{C}, V_{CC} = 5V$		1	μs	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS3668. All typicals are given for $V_{CC} = 5V$ and $T_A = 25^\circ\text{C}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: PRR = 100 kHz, 50% duty cycle, $Z_{OUT} \cong 50\Omega$, $t_r = t_f \leq 10 \text{ ns}$.

Note 2: C_L includes probe and jig capacitance.

DS1687/DS3687 Negative Voltage Relay Driver

General Description

The DS1687/DS3687 is a high voltage/current negative voltage relay driver having many features not available in present relay drivers.

PNP inputs provide both TTL/LS compatibility and high input impedance for low input loading.

Output leakage is specified over temperature at an output voltage of $-54V$. Minimum output breakdown (ac/latch breakdown) is specified over temperature at $-5mA$. This clearly defines the actual breakdown of the device since the circuit has incorporated in it an internal reference which does not allow output breakdown latching found in existing relay drivers. Additionally, this internal reference circuit feature will eliminate the need in most cases of an external clamping (inductive transient voltage protection) diode. When the output is turned "OFF" by input logic conditions the resulting inductive voltage transient seen at the output is detected by an internal zener reference. The reference then momentarily activates the output transistor long enough so that the relay energy is discharged. This feature eliminates the need of external circuit protection components and insures output transistor protection.

The outputs are Darlington connected transistors, which

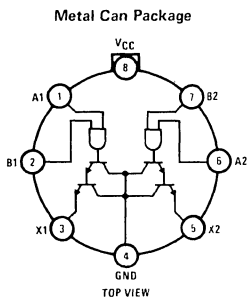
allow high current operation at low internal V_{CC} current levels—base drive for the output transistor is obtained from the load in proportion to the required loading conditions. Typical V_{CC} power with both outputs "ON" is 90 mW.

The circuit also features output transistor protection if the V_{CC} supply is lost by forcing the output into the high impedance "OFF" state with the same breakdown levels as when V_{CC} was applied.

Features

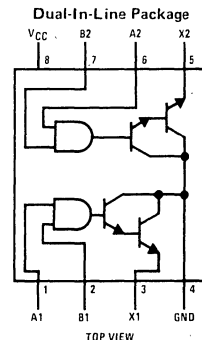
- TTL/LS/CMOS compatible inputs
- High impedance inputs (PNP's)
- High output voltage breakdown ($-65V$ typ)
- High output current capability (300 mA max)
- Internal protection circuit eliminates need for output protection diode
- Output breakdown protection if V_{CC} supply is lost
- Low V_{CC} power dissipation (90 mW (typ) both outputs "ON")
- Voltage and current levels compatible for use in telephone relay applications

Connection Diagrams



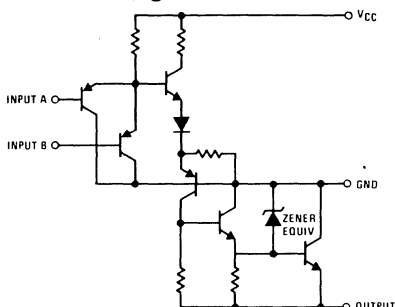
Pin 4 is in electrical contact with the case

**Order Number DS1687H
or DS3687H
See NS Package H08C**



**Order Number DS1687J-8,
DS3687J-8 or DS3687N
See NS Package J08A or N08A**

Schematic Diagram



Truth Table

Positive logic: $\overline{AB} = X$

A	B	OUTPUT X
0	0	1
1	0	1
0	1	1
1	1	0

Logic "0" output "ON"
Logic "1" output "OFF"

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	15V
Output Voltage	56V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1133 mW
Molded Package	1022 mW
TO-5 Package	787 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}			
DS1687	4.5	5.5	V
DS3687	4.75	5.25	V
Temperature, T_A			
DS1687	-55	+125	°C
DS3687	0	+70	°C

*Derate cavity package 7.6 mW/°C above 25°C; derate molded package 8.2 mW/°C above 25°C; derate TO-5 package 5.2 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

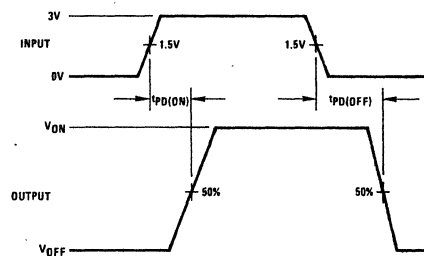
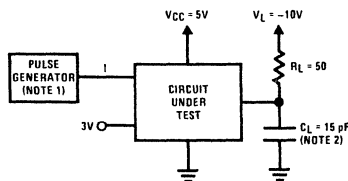
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V_{IH} Logical "1" Input Voltage		2.0			V	
I_{IH} Logical "1" Input Current	$V_{CC} = \text{Max}, V_{IN} = 5.5V$		1.0		μA	
V_{IL} Logical "0" Input Voltage				0.8	V	
I_{IL} Logical "0" Input Current	$V_{CC} = \text{Max}, V_{IN} = 0.4V$		-150	-250	μA	
V_{CD} Input Clamp Voltage	$V_{CC} = 5V, I_{CLAMP} = -12 \text{ mA}, T_A = 25^\circ C$		-1.0	-1.5	V	
V_{OH} Output Breakdown	$V_{CC} = \text{Max}, V_{IN} = 0V, I_{OUT} = -5 \text{ mA}$	-56	-65		V	
I_{OH} Output Leakage	$V_{CC} = \text{Max}, V_{IN} = 0V, V_{OUT} = -54V$		-0.5	-250	μA	
V_{OL} Output ON Voltage	$V_{CC} = \text{Min}, V_{IN} = 2V$	DS1687	$I_{OL} = -100 \text{ mA}$	-0.9	-1.1	V
			$I_{OL} = -300 \text{ mA}$	-1.0	-1.3	V
		DS3687	$I_{OL} = -100 \text{ mA}$	-0.9	-1.0	V
			$I_{OL} = -300 \text{ mA}$	-1.0	-1.2	V
$I_{CC(1)}$ Supply Current (Both Drivers)	$V_{CC} = \text{Max}, V_{IN} = 0V, \text{Outputs Open}$		2	4	mA	
$I_{CC(0)}$ Supply Current (Both Drivers)	$V_{CC} = \text{Max}, V_{IN} = 3V, \text{Outputs Open}$		18	28	mA	
$t_{PD(ON)}$ Propagation Delay to a Logical "0" (Output Turn ON)	$C_L = 15 \text{ pF}, V_L = -10V, R_L = 50\Omega, T_A = 25^\circ C, V_{CC} = 5V$		50		ns	
$t_{PD(OFF)}$ Propagation Delay to a Logical "1" (Output Turn OFF)	$C_L = 15 \text{ pF}, V_L = -10V, R_L = 50\Omega, T_A = 25^\circ C, V_{CC} = 5V$		1.0		μs	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS1687 and across the 0°C to +70°C range for the DS3687. All typicals are given for $V_{CC} = 5V$ and $T_A = 25^\circ C$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: PRR = 1 MHz, 50% duty cycle, $Z_{OUT} \approx 50\Omega, t_r = t_f \leq 10 \text{ ns}$.

Note 2: C_L includes probe and jig capacitance.

DS55450/DS75450 Series Dual Peripheral Drivers

General Description

The DS55450/DS75450 series of dual peripheral drivers are a family of versatile devices designed for use in systems that use TTL logic. Typical applications include high speed logic buffers, power drivers, relay drivers, lamp drivers, MOS drivers, bus drivers and memory drivers.

The DS75450 is a general purpose device featuring two standard Series 54/74 TTL gates and two uncommitted, high current, high voltage NPN transistors. The device offers the system designer the flexibility of tailoring the circuit to the application.

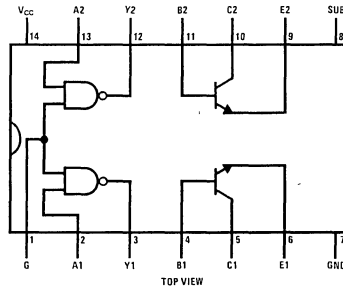
The DS55451/DS75451, DS55452/DS75452, DS55453/DS75453 and DS55454/DS75454 are dual peripheral

AND, NAND, OR and NOR drivers, respectively, (positive logic) with the output of the logic gates internally connected to the bases of the NPN output transistors.

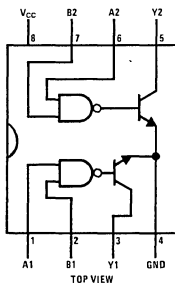
Features

- 300 mA output current capability
- High voltage outputs
- No output latch-up at 20V
- High speed switching
- Choice of logic function
- TTL compatible diode-clamped inputs
- Standard supply voltages
- Replaces TI "A" and "B" series

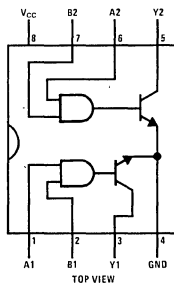
Connection Diagrams (Dual-In-Line and Metal Can Packages)



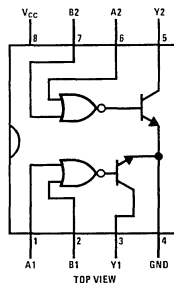
Order Number **DS75450J** or **DS75450N**
See NS Package J14A or N14A



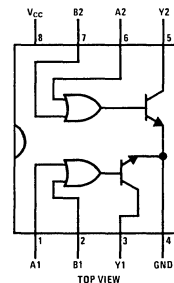
Order Number **DS55451J-8**,
DS75451J-8 or **DS75451N**



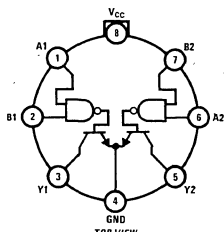
Order Number **DS55452J-8**,
DS75452J-8 or **DS75452N**
See NS Package J08A or N08A



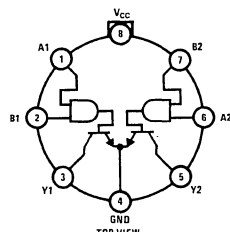
Order Number **DS55453J-8**,
DS75453J-8 or **DS75453N**
See NS Package J08A or N08A



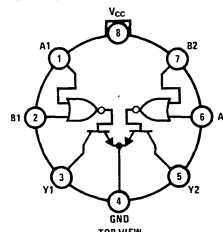
Order Number **DS55454J-8**,
DS75454J-8 or **DS75454N**



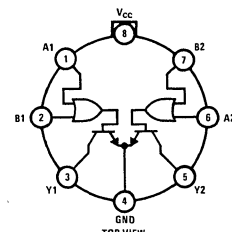
Order Number
DS55451H or **DS75451H**



Order Number
DS55452H or **DS75452H**
See NS Package H08C



Order Number
DS55453H or **DS75453H**
See NS Package H08C



Order Number
DS55454H or **DS75454H**

Absolute Maximum Ratings (Note 1)

Supply Voltage, (V _{CC}) (Note 2)	7.0V
Input Voltage	5.5V
Inter-emitter Voltage (Note 3)	5.5V
V _{CC} -to-Substrate Voltage DS75450	35V
Collector-to-Substrate Voltage DS75450	35V
Collector-Base Voltage DS75450	35V
Collector-Emitter Voltage (Note 4) DS75450	30V
Emitter-Base Voltage DS75450	5.0V
Output Voltage (Note 5) DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454	30V
Collector Current (Note 6) DS75450	300 mA
Output Current (Note 6) DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454	300 mA
DS75450 Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW
DS75451/2/3/4 Maximum Power Dissipation † at 25°C	
Cavity Package	1090 mW
Molded Package	957 mW
TO-5 Package	760 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	260°C

Operating Conditions (Note 7)

	MIN	MAX	UNITS
Supply Voltage, (V _{CC})			
DS5545X	4.5	5.5	V
DS7545X	4.75	5.25	V
Temperature, (T _A)			
DS5545X	-55	+125	°C
DS7545X	0	+70	°C

*Derate cavity package 8.7 mW/°C above 25°C; derate molded package 9.7 mW/°C above 25°C.

† Derate cavity package 7.3 mW/°C above 25°C; derate molded package 7.7 mW/°C above 25°C; derate TO-5 package 5.1 mW/°C above 25°C.

Electrical Characteristics DS75450 (Notes 8 and 9)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
TTL GATES					
V _{IH}	High Level Input Voltage (Figure 1)	2			V
V _{IL}	Low Level Input Voltage (Figure 2)			0.8	V
V _I	Input Clamp Voltage V _{CC} = Min, I _I = -12 mA, (Figure 3)			-1.5	V
V _{OH}	High Level Output Voltage V _{CC} = Min, V _{IL} = 0.8V, I _{OH} = -400µA, (Figure 2)	2.4	3.3		V
V _{OL}	Low Level Output Voltage V _{CC} = Min, V _{IH} = 2V, I _{OL} = 16 mA (Figure 1)		0.22	0.4	V
I _I	Input Current at Maximum Input Voltage V _{CC} = Max, V _I = 5.5V, (Figure 4)	Input A		1	mA
		Input G		2	mA
I _{IH}	High Level Input Current V _{CC} = Max, V _I = 2.4V, (Figure 4)	Input A		40	µA
		Input G		80	µA
I _{IL}	Low Level Input Current V _{CC} = Max, V _I = 0.4V, (Figure 3)	Input A		-1.6	mA
		Input G		-3.2	mA
I _{OS}	Short Circuit Output Current V _{CC} = Max, (Figure 5), (Note 10)	-18		-55	mA
I _{CCH}	Supply Current V _{CC} = Max, V _I = 0V, Outputs High, (Figure 6)	2	4		mA
I _{CCL}	Supply Current V _{CC} = Max, V _I = 5V, Outputs Low, (Figure 6)	6	11		mA
OUTPUT TRANSISTORS					
V _{(BR)ICBO}	Collector-Base Breakdown Voltage I _C = 100µA, I _E = 0	35			V
V _{(BR)ICER}	Collector-Emitter Breakdown Voltage I _C = 100µA, R _{BE} = 500Ω	30			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage I _E = 100µA, I _C = 0	5			V
h _{FE}	Static Forward Current Transfer Ratio V _{CE} = 3V, (Note 11)	T _A = +25°C	I _C = 100 mA	25	
			I _C = 300 mA	30	
		T _A = 0°C	I _C = 100 mA	20	
			I _C = 300 mA	25	
V _{BE}	Base-Emitter Voltage (Note 11)	I _B = 10 mA, I _C = 100 mA	0.85	1	V
		I _B = 30 mA, I _C = 300 mA	1.05	1.2	V
		I _B = 10 mA, I _C = 100 mA	0.25	0.4	V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage (Note 11)	I _B = 30 mA, I _C = 300 mA	0.5	0.7	V
		I _B = 10 mA, I _C = 100 mA			

Electrical Characteristics (Continued)

DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454 (Notes 8 and 9)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
V_{IH} High-Level Input Voltage	(Figure 7)		2			V	
V_{IL} Low-Level Input Voltage							
V_I Input Clamp Voltage	$V_{CC} = \text{Min}, I_I = -12 \text{ mA}$				-1.5	V	
V_{OL} Low-Level Output Voltage	$V_{CC} = \text{Min},$ (Figure 7)	$V_{IL} = 0.8 \text{ V}$	$I_{OL} = 100 \text{ mA}$	DS55451, DS55453	0.25	0.5	V
				DS75451, DS75453	0.25	0.4	V
			$I_{OL} = 300 \text{ mA}$	DS55451, DS55453	0.5	0.8	V
		DS75451, DS75453		0.5	0.7	V	
		$V_{IH} = 2 \text{ V}$	$I_{OL} = 100 \text{ mA}$	DS55452, DS55454	0.25	0.5	V
				DS75452, DS75454	0.25	0.4	V
$I_{OL} = 300 \text{ mA}$	DS55452, DS55454	0.5	0.8	V			
		DS75452, DS75454	0.5	0.7	V		
I_{OH} High-Level Output Current	$V_{CC} = \text{Min},$ (Figure 7)	$V_{OH} = 30 \text{ V}$	$V_{IH} = 2 \text{ V}$	DS55451, DS55453		300	μA
				DS75451, DS75453		100	μA
			$V_{IL} = 0.8 \text{ V}$	DS55452, DS55454		300	μA
				DS75452, DS75454		100	μA
I_I Input Current at Maximum Input Voltage	$V_{CC} = \text{Max}, V_I = 5.5 \text{ V},$ (Figure 9)				1	mA	
I_{IH} High-Level Input Current	$V_{CC} = \text{Max}, V_I = 2.4 \text{ V},$ (Figure 9)				40	μA	
I_{IL} Low-Level Input Current	$V_{CC} = \text{Max}, V_I = 0.4 \text{ V},$ (Figure 8)			-1	-1.6	mA	
I_{CCH} Supply Current, Outputs High	$V_{CC} = \text{Max},$ (Figure 10)	$V_I = 5 \text{ V}$	DS55451/DS75451	7	11	mA	
		$V_I = 0 \text{ V}$	DS55452/DS75452	11	14	mA	
		$V_I = 5 \text{ V}$	DS55453/DS75453	8	11	mA	
		$V_I = 0 \text{ V}$	DS55454/DS75454	13	17	mA	
I_{CCL} Supply Current, Outputs Low	$V_{CC} = \text{Max},$ (Figure 10)	$V_I = 0 \text{ V}$	DS55451/DS75451	52	65	mA	
		$V_I = 5 \text{ V}$	DS55452/DS75452	56	71	mA	
		$V_I = 0 \text{ V}$	DS55453/DS75453	54	68	mA	
		$V_I = 5 \text{ V}$	DS55454/DS75454	61	79	mA	

Switching Characteristics

DS75450 ($V_{CC} = 5 \text{ V}, T_A = 25^\circ\text{C}$)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-To-High Level Output	$C_L = 15 \text{ pF}$	$R_L = 400\Omega$, TTL Gates, (Figure 12)		12	22	ns
		$R_L = 50\Omega$, $I_C \approx 200 \text{ mA}$, Gates and Transistors Combined, (Figure 14)		20	30	ns
t_{PHL} Propagation Delay Time, High-To-Low Level Output	$C_L = 15 \text{ pF}$	$R_L = 400\Omega$, TTL Gates, (Figure 12)		8	15	ns
		$R_L = 50\Omega$, $I_C \approx 200 \text{ mA}$, Gates and Transistors Combined, (Figure 14)		20	30	ns
t_{TLH} Transition Time, Low-To-High Level Output	$C_L = 15 \text{ pF}, R_L = 50\Omega, I_C \approx 200 \text{ mA}$, Gates and Transistors Combined, (Figure 14)			7	12	ns
t_{THL} Transition Time, High-To-Low Level Output	$C_L = 15 \text{ pF}, R_L = 50\Omega, I_C \approx 200 \text{ mA}$, Gates and Transistors Combined, (Figure 14)			9	15	ns
V_{OH} High-Level Output Voltage After Switching	$V_S = 20 \text{ V}, I_C \approx 300 \text{ mA}, R_{BE} = 500\Omega,$ (Figure 15)		$V_S - 6.5$			mV
t_D Delay Time	$I_C = 200 \text{ mA}, I_{B(1)} = 20 \text{ mA}, I_B = -40 \text{ mA}, V_{BE(OFF)} = -1 \text{ V}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 13), (Note 12)			8	15	ns
t_R Rise Time	$I_C = 200 \text{ mA}, I_{B(1)} = 20 \text{ mA}, I_B = -40 \text{ mA}, V_{BE(OFF)} = -1 \text{ V}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 13), (Note 12)			12	20	ns
t_S Storage Time	$I_C = 200 \text{ mA}, I_{B(1)} = 20 \text{ mA}, I_B = -40 \text{ mA}, V_{BE(OFF)} = -1 \text{ V}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 13), (Note 12)			7	15	ns
t_F Fall Time	$I_C = 200 \text{ mA}, I_{B(1)} = 20 \text{ mA}, I_B = -40 \text{ mA}, V_{BE(OFF)} = -1 \text{ V}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 13), (Note 12)			6	15	ns

Switching Characteristics (Continued)

DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454 ($V_{CC} = 5V$, $T_A = 25^\circ C$)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
t_{PLH}	Propagation Delay Time, Low-To-High Level Output	$C_L = 15 \text{ pF}$, $R_L = 50\Omega$, $I_O \approx 200 \text{ mA}$, (Figure 14)	DS55451/DS75451	18	25	ns	
			DS55452/DS75452	26	35	ns	
			DS55453/DS75453	18	25	ns	
			DS55454/DS75454	27	35	ns	
t_{PHL}	Propagation Delay Time, High-To-Low Level Output	$C_L = 15 \text{ pF}$, $R_L = 50\Omega$, $I_O \approx 200 \text{ mA}$, (Figure 14)	DS55451/DS75451	18	25	ns	
			DS55452/DS75452	24	35	ns	
			DS55453/DS75453	16	25	ns	
			DS55454/DS75454	24	35	ns	
t_{TLH}	Transition Time, Low-To-High Level Output	$C_L = 15 \text{ pF}$, $R_L = 50\Omega$, $I_O \approx 200 \text{ mA}$, (Figure 14)		5	8	ns	
t_{THL}	Transition Time, High-To-Low Level Output	$C_L = 15 \text{ pF}$, $R_L = 50\Omega$, $I_O \approx 200 \text{ mA}$, (Figure 14)		7	12	ns	
V_{OH}	High-Level Output Voltage After Switching	$V_S = 20V$, $I_O \approx 300 \text{ mA}$, (Figure 15)	$V_S - 6.5$			mV	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Voltage values are with respect to network ground terminal unless otherwise specified.

Note 3: The voltage between two emitters of a multiple-emitter transistor.

Note 4: Value applies when the base-emitter resistance (R_{BE}) is equal to or less than 500Ω .

Note 5: The maximum voltage which should be applied to any output when it is in the "OFF" state.

Note 6: Both halves of these dual circuits may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous dissipation rating.

Note 7: For the DS75450 only, the substrate (pin 8) must always be at the most-negative device voltage for proper operation.

Note 8: Unless otherwise specified min/max limits apply across the $-55^\circ C$ to $+125^\circ C$ temperature range for the DS55450 series and across the $0^\circ C$ to $+70^\circ C$ range for the DS75450 series. All typicals are given for $V_{CC} = +5V$ and $T_A = 25^\circ C$.

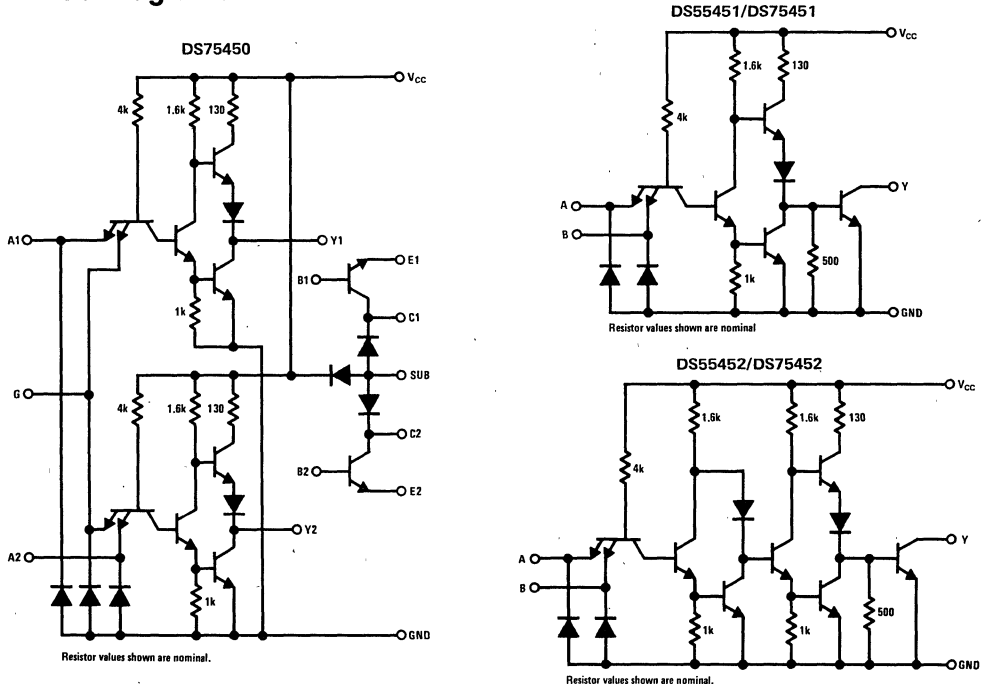
Note 9: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 10: Only one output at a time should be shorted.

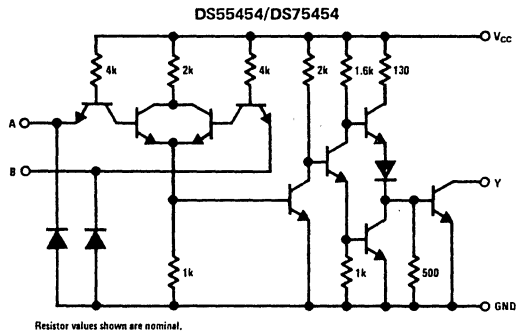
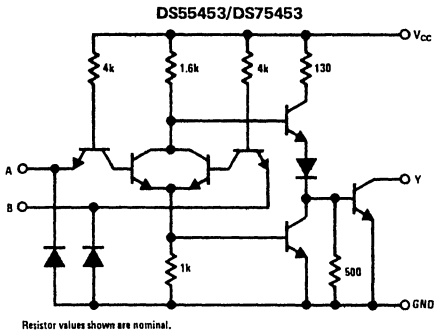
Note 11: These parameters must be measured using pulse techniques. $t_W = 300\mu s$, duty cycle $< 2\%$.

Note 12: Applies to output transistors only.

Schematic Diagrams



Schematic Diagrams (Continued)



Truth Tables (H = high level, L = low level)

DS55451/DS75451

A	B	Y
L	L	L (ON State)
L	H	L (ON State)
H	L	L (ON State)
H	H	H (OFF State)

DS55452/DS75452

A	B	Y
L	L	H (OFF State)
L	H	H (OFF State)
H	L	H (OFF State)
H	H	L (ON State)

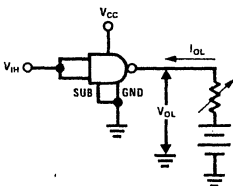
DS55453/DS75453

A	B	Y
L	L	L (ON State)
L	H	H (OFF State)
H	L	H (OFF State)
H	H	H (OFF State)

DS55454/DS75454

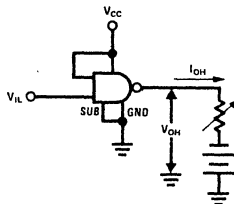
A	B	Y
L	L	H (OFF State)
L	H	L (ON State)
H	L	L (ON State)
H	H	L (ON State)

DC Test Circuits



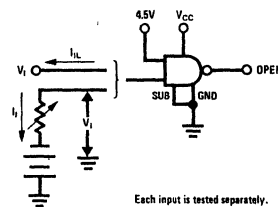
Both inputs are tested simultaneously.

FIGURE 1. V_{IH} , V_{OL}



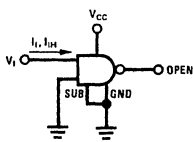
Each input is tested separately.

FIGURE 2. V_{IL} , V_{OH}



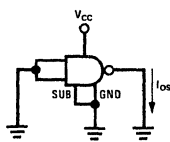
Each input is tested separately.

FIGURE 3. V_I , I_{IL}



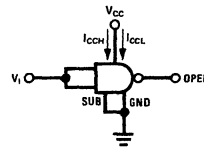
Each input is tested separately.

FIGURE 4. I_I , I_{IH}



Each gate is tested separately.

FIGURE 5. I_{OS}



Both gates are tested simultaneously.

FIGURE 6. I_{CCH} , I_{CCL}

DC Test Circuits (Continued)

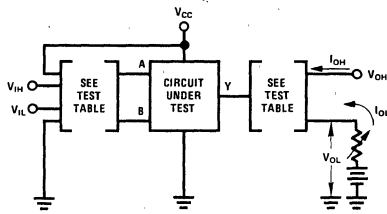


FIGURE 7. V_{IH} , V_{IL} , I_{OH} , V_{OH} , I_{OL} , V_{OL}

CIRCUIT	INPUT UNDER TEST	OTHER INPUT	OUTPUT	
			APPLY	MEASURE
DS54451	V_{IH} V_{IL}	V_{IH} V_{CC}	V_{OH} I_{OL}	I_{OH} V_{OL}
DS54452	V_{IH} V_{IL}	V_{IH} V_{CC}	I_{OL} V_{OH}	V_{OL} I_{OH}
DS54453	V_{IH} V_{IL}	Gnd V_{IL}	V_{OH} I_{OL}	I_{OH} V_{OL}
DS54454	V_{IH} V_{IL}	Gnd V_{IL}	I_{OL} V_{OH}	V_{OL} I_{OH}

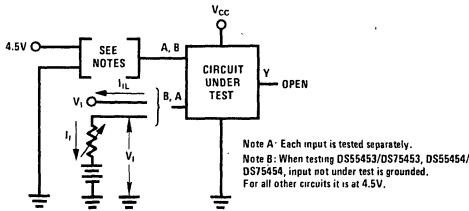


FIGURE 8. V_I , I_{IL}

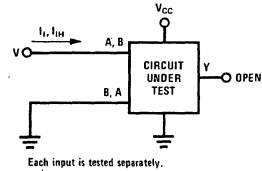


FIGURE 9. I_I , I_{IH}

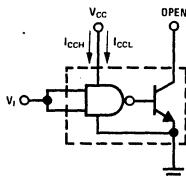


FIGURE 10. I_{CCH} , I_{CCL} for AND, NAND Circuits

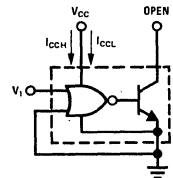
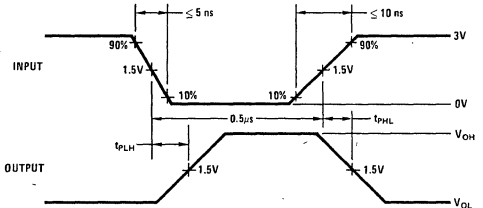
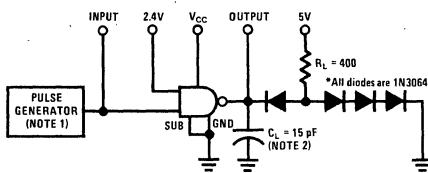


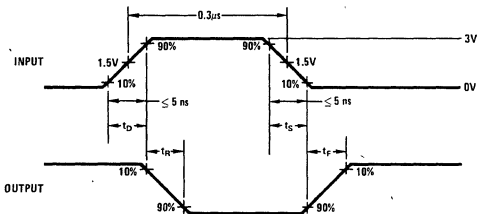
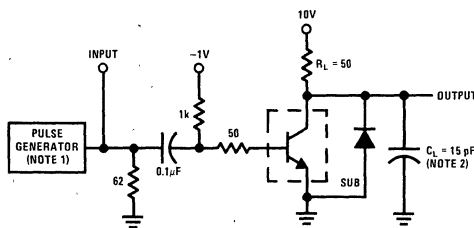
FIGURE 11. I_{CCH} , I_{CCL} for OR, NOR Circuits

AC Test Circuits and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: PRR = 1 MHz, $Z_{OUT} \approx 50\Omega$.
 Note 2: C_L includes probe and jig capacitance.

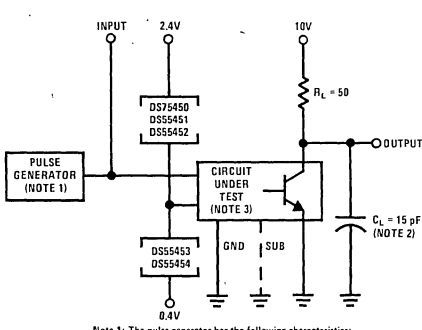
FIGURE 12. Propagation Delay Times, Each Gate (DS75450 Only)



Note 1: The pulse generator has the following characteristics: duty cycle $\le 1\%$, $Z_{OUT} \approx 50\Omega$.
 Note 2: C_L includes probe and jig capacitance.

FIGURE 13. Switching Times, Each Transistor (DS75450 Only)

AC Test Circuits and Switching Time Waveforms (Continued)



Note 1: The pulse generator has the following characteristics: PRR = 1.0 MHz, $Z_{OUT} \approx 50\Omega$.
 Note 2: C_L includes probe and jig capacitance.
 Note 3: When testing DS75450, connect output Y to transistor base and ground the substrate terminal.

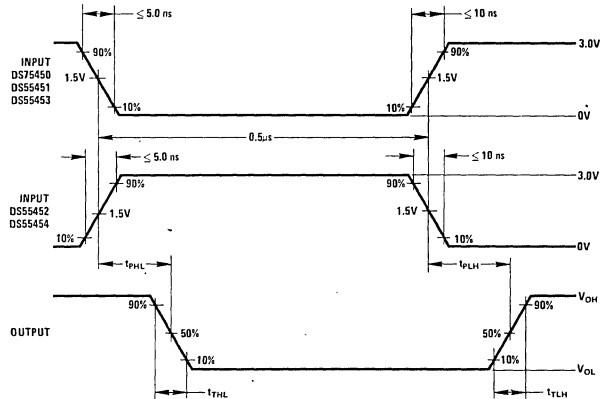
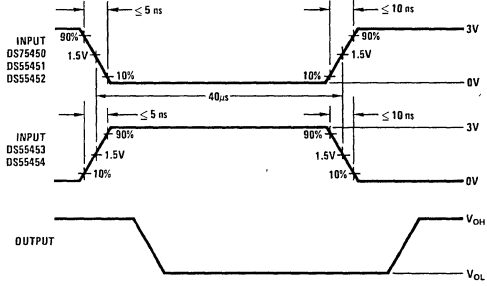
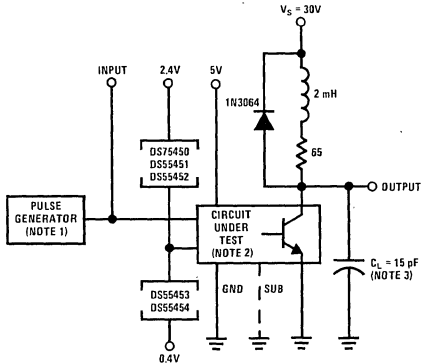


FIGURE 14. Switching Times of Complete Drivers



Note 1: The pulse generator has the following characteristics: PRR = 12.5 kHz, $Z_{OUT} = 50\Omega$.
 Note 2: When testing DS75450, connect output Y to transistor base with a 500Ω resistor from there to ground and ground the substrate terminal.
 Note 3: C_L includes probe and jig capacitance.

FIGURE 15. Latch-Up Test of Complete Drivers

Typical Performance Characteristics

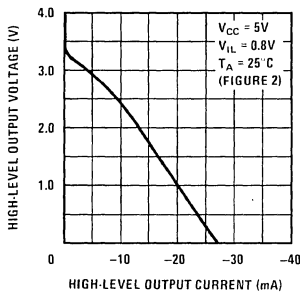


FIGURE 16. DS75450 TTL Gate High-Level Output Voltage vs High-Level Output Current

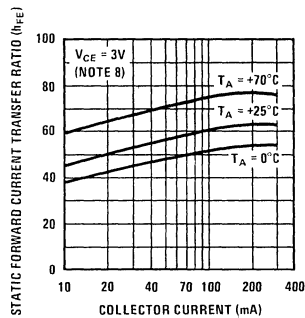


FIGURE 17. DS75450 Transistor Static Forward Current Transfer Ratio vs Collector Current

Typical Performance Characteristics (Continued)

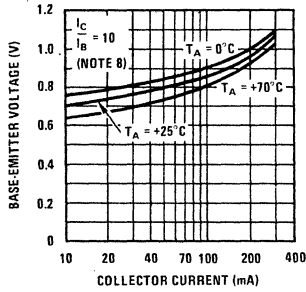


FIGURE 18. DS75450 Transistor Base-Emitter Voltage vs Collector Current

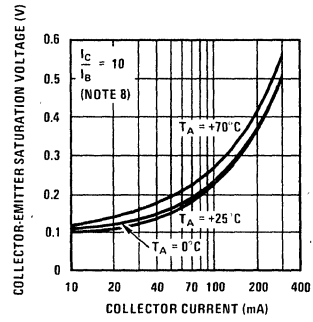


FIGURE 19. Transistor Collector-Emitter Saturation Voltage vs Collector Current

Typical Applications

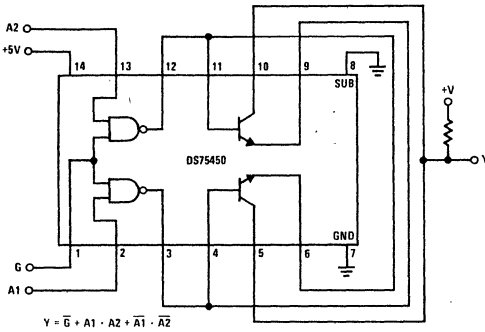


FIGURE 20. Gated Comparator

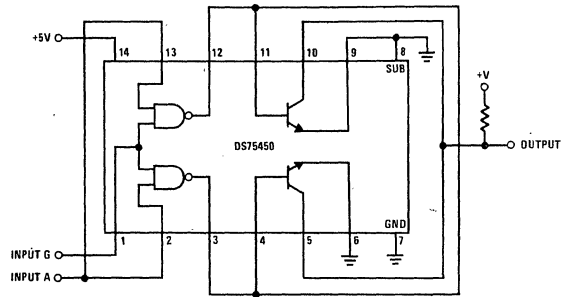


FIGURE 21. 500 mA Sink

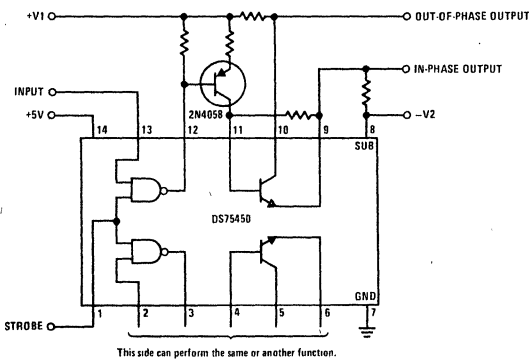


FIGURE 22. Floating Switch

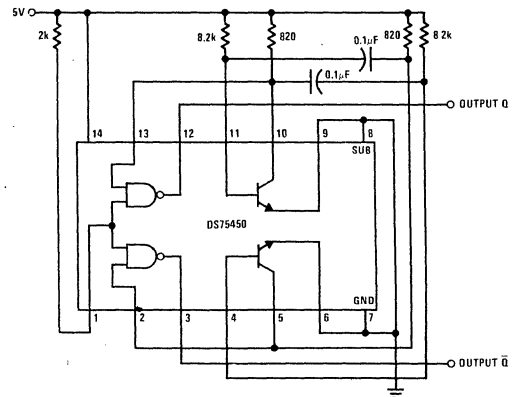


FIGURE 23. Square-Wave Generator

Typical Applications (Continued)

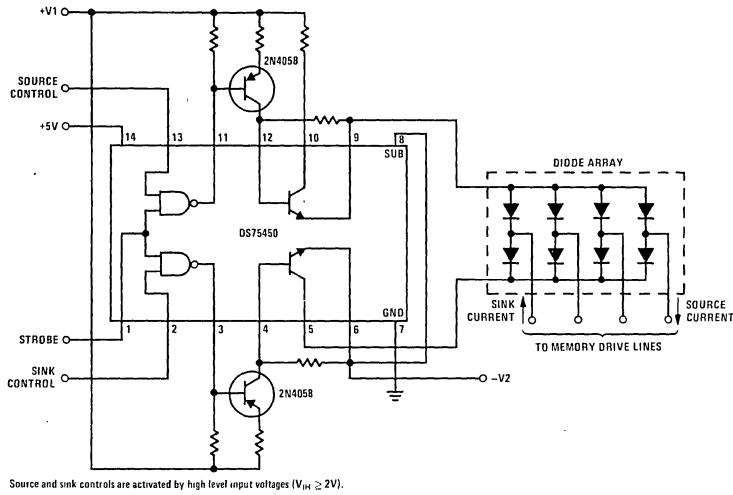


FIGURE 24. Core Memory Driver

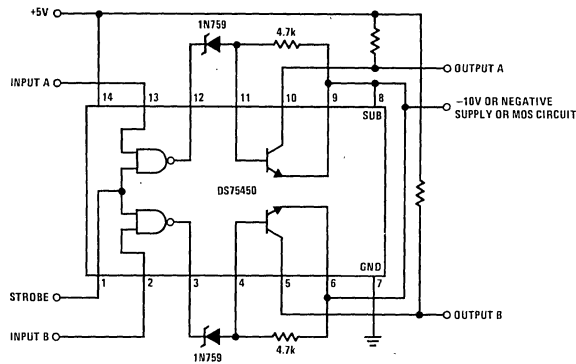


FIGURE 25. Dual TTL-to-MOS Driver

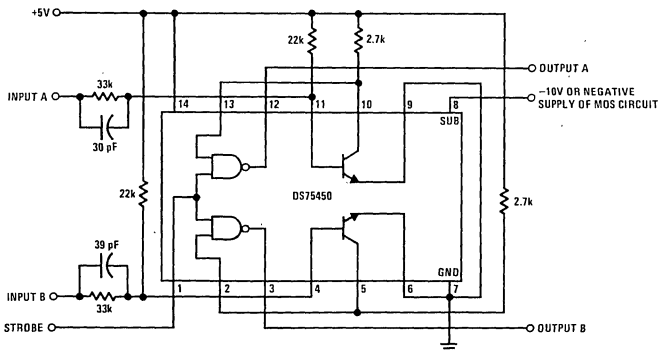


FIGURE 26. Dual MOS-to-TTL Driver

Typical Applications (Continued)

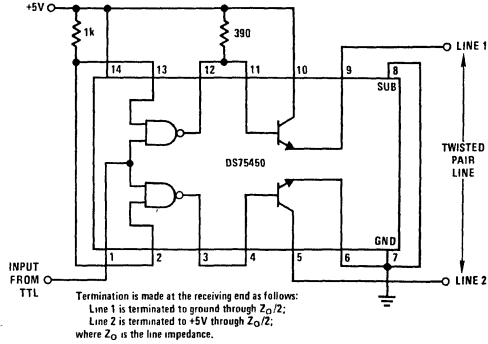


FIGURE 27. Balanced Line Driver

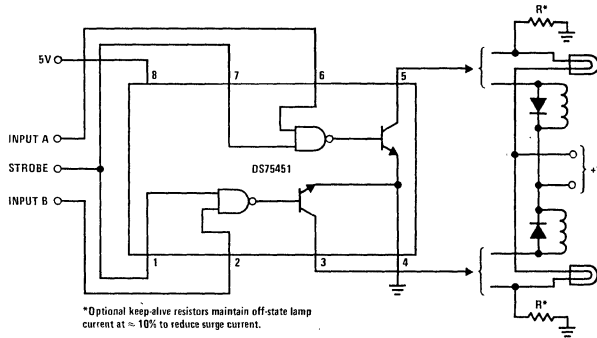


FIGURE 28. Dual Lamp or Relay Driver

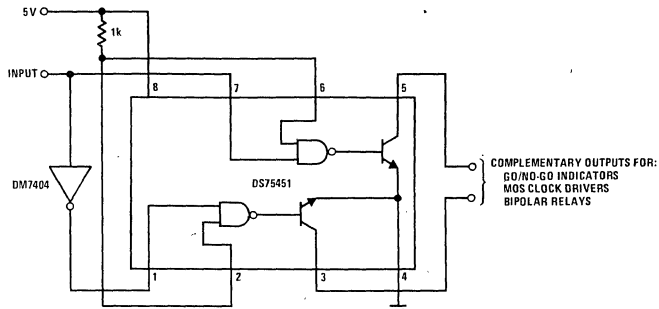


FIGURE 29. Complementary Driver

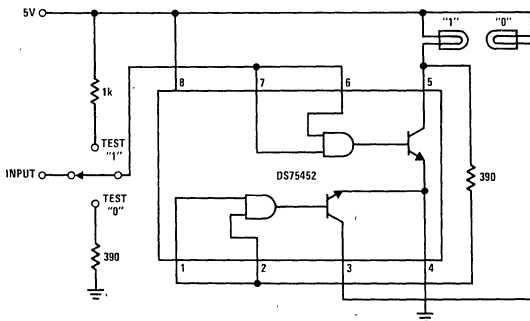


FIGURE 30. TTL or DTL Positive Logic-Level Detector

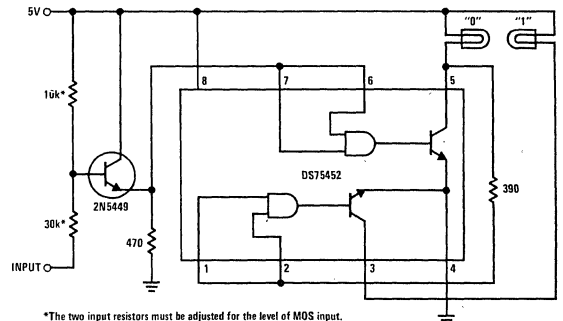


FIGURE 31. MOS Negative Logic-Level Detector

Typical Applications (Continued)

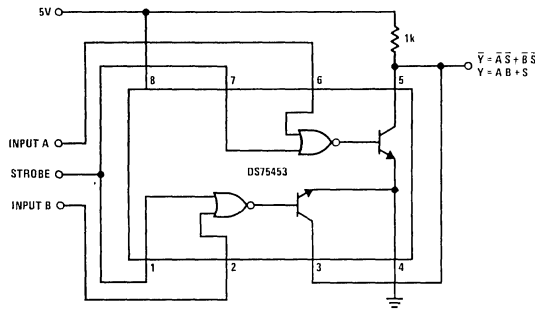
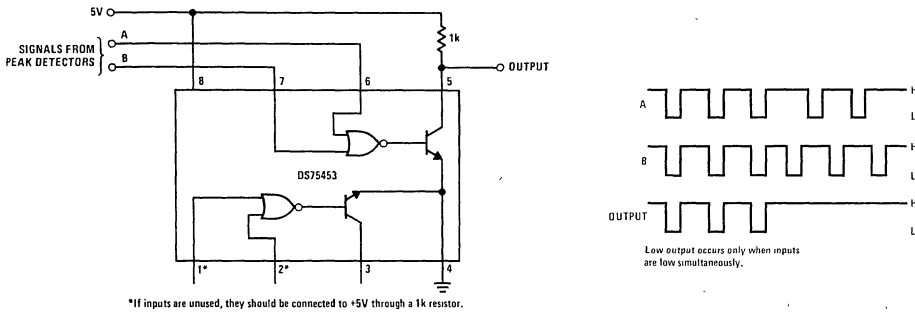


FIGURE 32. Logic Signal Comparator



*If inputs are unused, they should be connected to +5V through a 1k resistor.

FIGURE 33. In-Phase Detector

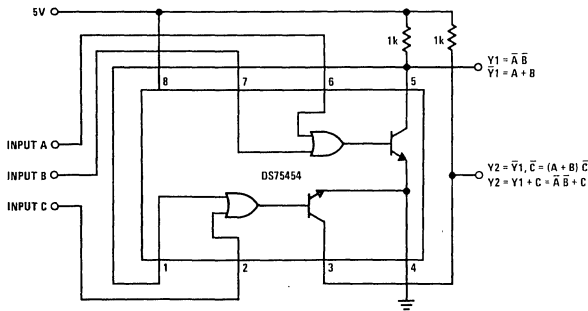


FIGURE 34. Multifunction Logic-Signal Comparator

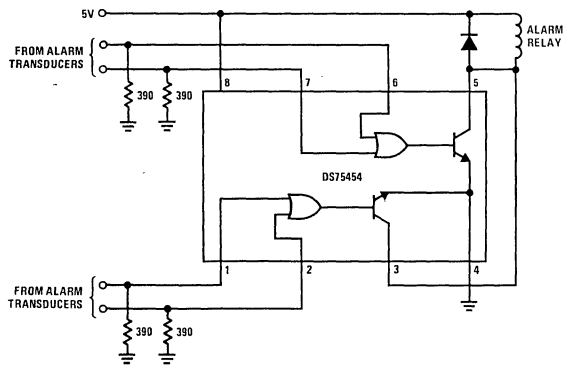


FIGURE 35. Alarm Detector

DS55461/2/3/4, DS75461/2/3/4 Series Dual Peripheral Drivers

General Description

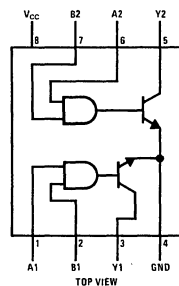
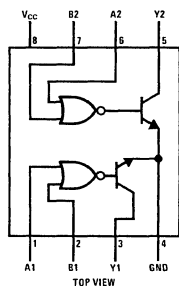
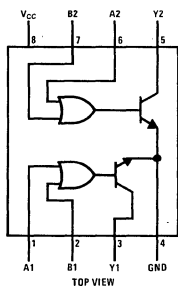
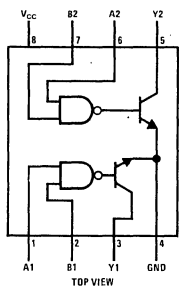
The DS55461/2/3/4 series of dual peripheral drivers are functionally interchangeable with DS55451/2/3/4 series peripheral drivers, but are designed for use in systems that require higher breakdown voltages at the expense of slightly slower switching speeds. Typical applications include power drivers, logic buffers, lamp drivers, relay drivers, MOS drivers, line drivers and memory drivers.

The DS55461/DS75461, DS55462/DS75462, DS55463/DS75463 and DS55464/DS75464 are dual peripheral AND, NAND, OR and NOR drivers, respectively, (positive logic) with the output of the logic gates internally connected to the bases of the NPN output transistors.

Features

- 300 mA output current capability
- High voltage outputs
- No output latch-up at 30V
- Medium speed switching
- Circuit flexibility for varied applications and choice of logic function
- TTL compatible diode-clamped inputs
- Standard supply voltages

Connection Diagrams (Dual-In-Line and Metal Can Packages)



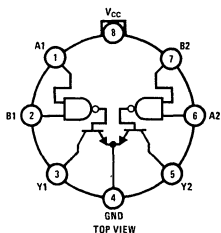
Order Number DS55461J-8, DS75461J-8 or DS75461N

Order Number DS55462J-8, DS75462J-8 or DS75462N

Order Number DS55463J-8, DS75463J-8 or DS75463N

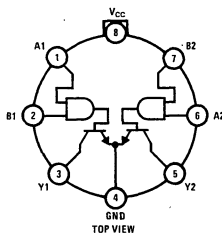
Order Number DS55464J-8, DS75464J-8 or DS75464N

See NS Package J08A or N08A



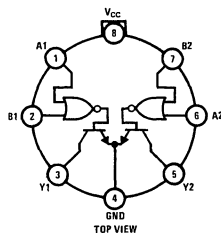
Pin 4 is in electrical contact with the case.

Order Number DS55461H or DS75461H



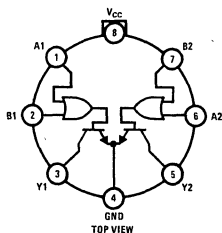
Pin 4 is in electrical contact with the case.

Order Number DS55462H or DS75462H



Pin 4 is in electrical contact with the case.

Order Number DS55463H or DS75463H



Pin 4 is in electrical contact with the case.

Order Number DS55464H or DS75464H

See NS Package H08C

Absolute Maximum Ratings (Note 1)

Supply Voltage (Note 2)	7V
Input Voltage	5.5V
Inter-emitter Voltage (Note 3)	5.5V
Output Voltage (Note 4)	
DS55461/DS75461, DS55462/DS75462, DS55463/DS75463, DS55464/DS75464	35V
Output Current (Note 5)	
DS55461/DS75461, DS55462/DS75462, DS55463/DS75463, DS55464/DS75464	300 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1090 mW
Molded Package	957 mW
TO-5 Package	760 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	260°C

*Derate cavity package 7.3 mW/°C above 25°C; derate molded package 7.7 mW/°C above 25°C; derate TO-5 package 5.1 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS5546X	4.5	5.5	V
DS7546X	4.75	5.25	V
Temperature (T _A)			
DS5546X	-55	+125	°C
DS7546X	0	+70	°C

Electrical Characteristics

DS55461/DS75461, DS55462/DS75462, DS55463/DS75463, DS55464/DS75464 (Notes 6 and 7)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
V _{IH}	High Level Input Voltage	(Figure 1)	2			V	
V _{IL}	Low Level Input Voltage	(Figure 1)			0.8	V	
V _I	Input Clamp Voltage	V _{CC} = Min, I _I = -12 mA		-1.2	-1.5	V	
V _{OL}	Low Level Output Voltage	V _{CC} = Min, (Figure 1)	DS55461, V _{IL} = 0.8V	I _{OL} = 100 mA	0.15	0.5	V
				I _{OL} = 300 mA	0.36	0.8	V
			DS55462, V _{IH} = 2V	I _{OL} = 100 mA	0.16	0.5	V
				I _{OL} = 300 mA	0.35	0.8	V
			DS55463, V _{IL} = 0.8V	I _{OL} = 100 mA	0.18	0.5	V
				I _{OL} = 300 mA	0.39	0.8	V
			DS55464, V _{IH} = 2V	I _{OL} = 100 mA	0.17	0.5	V
				I _{OL} = 300 mA	0.38	0.8	V
			DS75461, V _{IL} = 0.8V	I _{OL} = 100 mA	0.15	0.4	V
				I _{OL} = 300 mA	0.36	0.7	V
			DS75462, V _{IH} = 2V	I _{OL} = 100 mA	0.16	0.4	V
				I _{OL} = 300 mA	0.35	0.7	V
			DS75463, V _{IL} = 0.8V	I _{OL} = 100 mA	0.18	0.4	V
				I _{OL} = 300 mA	0.39	0.7	V
DS75464, V _{IH} = 2V	I _{OL} = 100 mA	0.17	0.4	V			
	I _{OL} = 300 mA	0.38	0.7	V			
I _{OH}	High Level Output Current	V _{CC} = Min, V _{OH} = 35V, (Figure 1)	V _{IH} = 2V	DS55461, DS55463		300	μA
				DS75461, DS75463		100	μA
				DS55462, DS55464		300	μA
			V _{IL} = 0.8V	DS75462, DS75464		100	μA
I _I	Input Current at Maximum Input Voltage	V _{CC} = Max, V _I = 5.5V, (Figure 3)			1	mA	
I _{IH}	High Level Input Current	V _{CC} = Max, V _I = 2.4V, (Figure 3)			40	μA	
I _{IL}	Low Level Input Current	V _{CC} = Max, V _I = 0.4V, (Figure 2)		-1	-1.6	mA	
I _{CC}	Supply Current	V _{CC} = Max, Outputs High, (Figures 4 and 5)	V _I = 5V	DS55461/ DS75461, DS55463/ DS75463	8	11	mA
				DS55462/ DS75462	13	17	mA
			V _I = 0V	DS55464/ DS75464	14	19	mA

Electrical Characteristics (Continued)

DS55461/DS75461, DS55462/DS75462, DS55463/DS75463, DS55464/DS75464 (Notes 6 and 7)

PARAMETER	CONDITIONS			MIN	TYP	MAX	UNITS
I_{CC} Supply Current	$V_{CC} = \text{Max, Outputs Low, (Figures 4 and 5)}$	$V_I = 0V$	DS55461/ DS75461		61	76	mA
			DS55463/ DS75463		63	76	mA
		$V_I = 5V$	DS55462/ DS75462		65	76	mA
			DS55464/ DS75464		72	85	mA

Switching Characteristics

DS55461/DS75461, DS55462/DS75462, DS55463/DS75463, DS55464/DS75464 $V_{CC} = 5V, T_A = 25^\circ C$

PARAMETER	CONDITIONS			MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-To-High Level Output	$I_O \approx 200 \text{ mA}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 6)		DS55461/ DS75461, DS55463/ DS75463		45	55	ns
			DS55462/ DS75462, DS55464/ DS75464		50	65	ns
t_{PHL} Propagation Delay Time, High-To-Low Level Output	$I_O \approx 200 \text{ mA}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 6)		DS55461/ DS75461, DS55463/ DS75463		30	40	ns
			DS55462/ DS75462, DS55464/ DS75464		40	50	ns
t_{TLH} Transition Time, Low-To-High Level Output	$I_O \approx 200 \text{ mA}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 6)		DS55461/ DS75461		8	20	ns
			DS55462/ DS75462		12	25	ns
			DS55463/ DS75463		8	25	ns
			DS55464/ DS75464		12	20	ns
t_{THL} Transition Time, High-To-Low Level Output	$I_O \approx 200 \text{ mA}, C_L = 15 \text{ pF}, R_L = 50\Omega,$ (Figure 6)		DS55461/ DS75461		10	20	ns
			DS55462/ DS75462, DS55464/ DS75464		15	20	ns
			DS55463/ DS75463		10	25	ns
			DS55464/ DS75464		10	25	ns
V_{OH} High-Level Output Voltage After Switching	$V_S = 30V, I_O \approx 300 \text{ mA},$ (Figure 7)			$V_S - 10$			mV

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Voltage values are with respect to network ground terminal unless otherwise specified.

Note 3: This is the voltage between two emitters of a multiple-emitter transistor.

Note 4: This is the maximum voltage which should be applied to any output when it is in the "OFF" state.

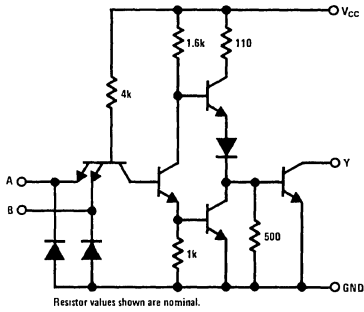
Note 5: Both halves of these dual circuits may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous dissipation rating.

Note 6: Unless otherwise specified min/max limits apply across the $-55^\circ C$ to $+125^\circ C$ temperature range for the DS55XXX series and across the $0^\circ C$ to $+70^\circ C$ range for the DS75XXX series. All typicals are given for $V_{CC} = +5V$ and $T_A = 25^\circ C$.

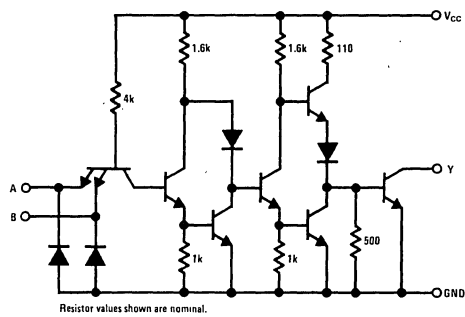
Note 7: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Schematic Diagrams

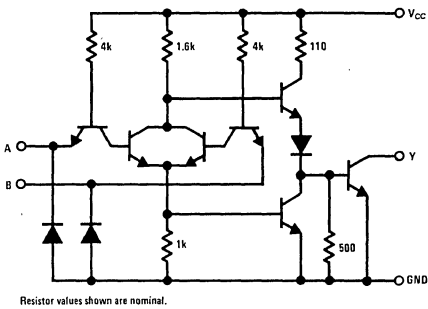
DS55461/DS75461



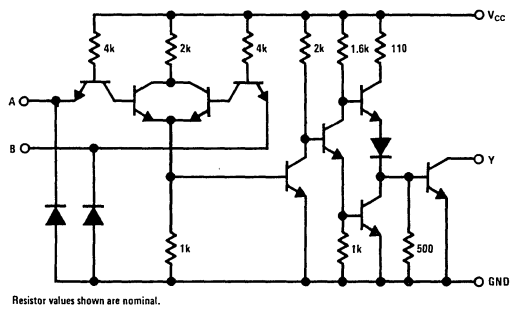
DS55462/DS75462



DS55463/DS75463



DS55464/DS75464



Truth Tables (H = high level, L = low level)

DS55461/DS75461

A	B	Y
L	L	L (ON State)
L	H	L (ON State)
H	L	L (ON State)
H	H	H (OFF State)

DS55462/DS75462

A	B	Y
L	L	H (OFF State)
L	H	H (OFF State)
H	L	H (OFF State)
H	H	L (ON State)

DS55463/DS75463

A	B	Y
L	L	L (ON State)
L	H	H (OFF State)
H	L	H (OFF State)
H	H	H (OFF State)

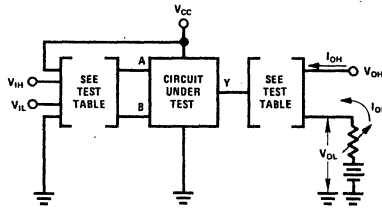
DS55464/DS75464

A	B	Y
L	L	H (OFF State)
L	H	L (ON State)
H	L	L (ON State)
H	H	L (ON State)

DS55461/62/63/64,
DS75461/62/63/64 Series

3

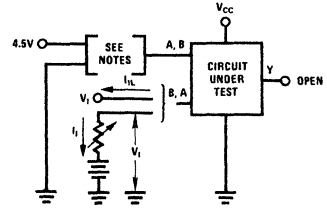
DC Test Circuits



CIRCUIT	INPUT UNDER TEST	OTHER INPUT	OUTPUT	
			APPLY	MEASURE
DS55461	V_{IH}	V_{IH}	V_{OH}	I_{OH}
	V_{IL}	V_{CC}	I_{OL}	V_{OL}
DS55462	V_{IH}	V_{IH}	I_{OL}	V_{OL}
	V_{IL}	V_{CC}	V_{OH}	I_{OH}
DS55463	V_{IH}	Gnd	V_{OH}	I_{OH}
	V_{IL}	V_{IL}	I_{OL}	V_{OL}
DS55464	V_{IH}	Gnd	I_{OL}	V_{OL}
	V_{IL}	V_{IL}	V_{OH}	I_{OH}

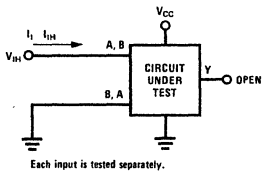
Each input is tested separately.

FIGURE 1. V_{IH} , V_{IL} , I_{OH} , V_{OL}



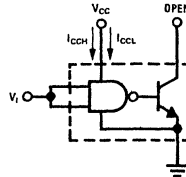
Note 1: Each input is tested separately.
 Note 2: When testing DS55463/DS75463 and DS75464, input not under test is grounded.
 For all other circuits it is at 4.5V.

FIGURE 2. V_I , I_{IL}



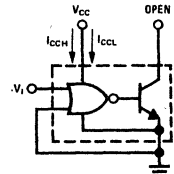
Each input is tested separately.

FIGURE 3. I_I , I_{IH}



Both gates are tested simultaneously.

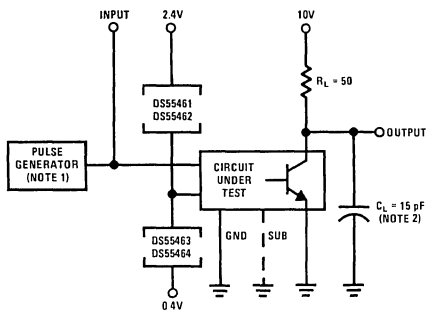
FIGURE 4. I_{CCH} , I_{CCL} for AND, NAND Circuits



Both gates are tested simultaneously.

FIGURE 5. I_{CCH} , I_{CCL} for OR, NOR Circuits

Switching Characteristics



Note 1: The pulse generator has the following characteristics:
PRR = 1 MHz, $Z_{OUT} = 50\Omega$.
Note 2: C_L includes probe and jig capacitance.

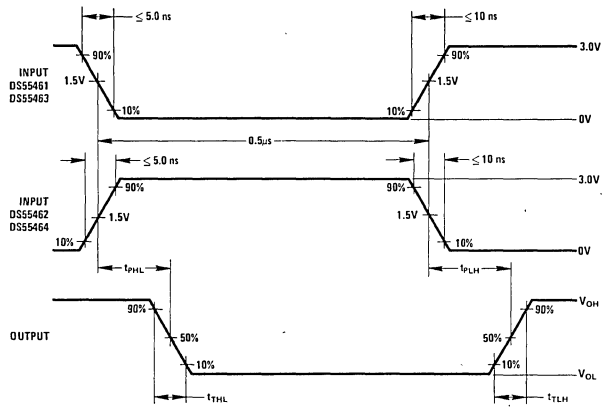
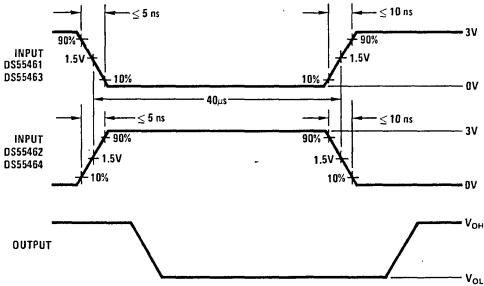
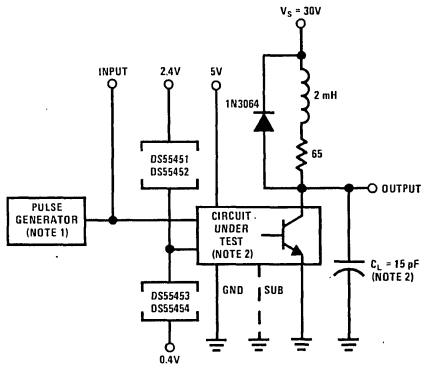


FIGURE 6. Switching Times of Complete Drivers



Note 1: The pulse generator has the following characteristics:
PRR = 12.5 kHz, $Z_{OUT} = 50\Omega$.
Note 2: C_L includes probe and jig capacitance.

FIGURE 7. Latch-Up Test of Complete Drivers

Safe Operating Areas for Peripheral Drivers

National Semiconductor
Application Note 213
Bill Fowler
October 1978



Peripheral Drivers is a broad definition given to Interface Power devices. The devices generally have open-collector output transistors that can switch hundreds of milliamps at high voltage, and are driven by standard Digital Logic gates. They serve many applications such as: Relay Drivers, Printer Hammer Drivers, Lamp Drivers, Bus Drivers, Core Memory Drivers, Voltage Level Transistors, and etc. Most IC devices have a specified maximum load such as one TTL gate can drive ten other TTL gates. Peripheral drivers have many varied load situations depending on the application, and requires the design engineer to interpret the limitations of the device vs its application. The major considerations are *Peak Current*, *Breakdown Voltage*, and *Power Dissipation*.

OUTPUT CURRENT AND VOLTAGE CHARACTERISTICS

Figure 1 shows the circuit of a typical peripheral driver, the DS75451. The circuit is equivalent to a TTL Gate driving a 300 mA output transistor. Figure 2 shows the characteristics of the output transistor when it is ON and when it is OFF. The output transistor is capable of sinking more than one amp of current when it is ON, and is specified at a $V_{OL} = 0.7V$ at 300 mA. The output transistor is also specified to operate with voltages up to 30V without breaking down, but there is more to that as shown by the breakdown voltages labeled BV_{CES} , BV_{CER} , and LV_{CEO} .

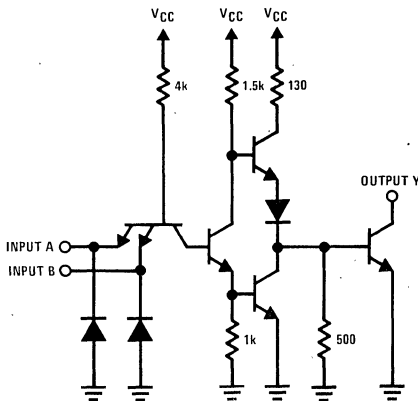


FIGURE 1. Typical Peripheral Driver DS75451

BV_{CES} corresponds to the breakdown voltage when the output transistor is held off by the lower output transistor of the TTL gate, as would happen if the power supply (V_{CC}) was 5V. BV_{CER} corresponds to the breakdown voltage when the output transistor is held off by, the 500 resistor, as would happen if the power supply (V_{CC}) was off (0V). LV_{CEO} corresponds to the breakdown voltage of the output transistor if it could be measured with the base open. LV_{CEO} can be measured by exceeding the breakdown voltage BV_{CES} and measuring the voltage at output currents

of 1 to 10 mA on a transistor curve tracer (LV_{CEO} is sometimes measured in an Inductive Latch-Up Test). Observe that all breakdown voltages converge on LV_{CEO} at high currents, and that destructive secondary breakdown voltage occurred (shown as dotted line) at high currents and high voltage corresponding to exceeding the power dissipation of the device. The characteristics of secondary breakdown voltage vary with the length of time the condition exists, device temperature, voltage, and current.

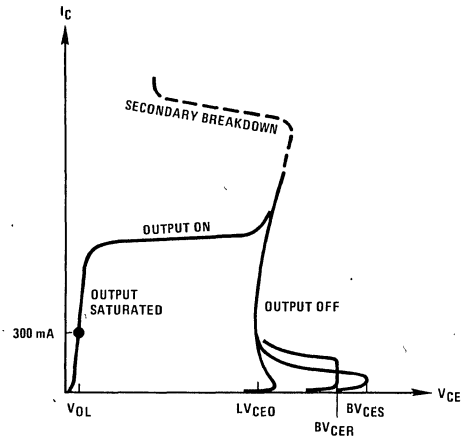


FIGURE 2. Output Characteristics ON and OFF

OUTPUT TRANSFER CHARACTERISTICS VS INDUCTIVE AND CAPACITIVE LOADS

Figure 3 shows the switching transfer characteristics superimposed on the DC characteristics of the output transistor for an inductive load. Figure 4 shows the switching transfer characteristics for a capacitor load. In both cases in these examples, the load voltage (V_B) exceeds LV_{CEO} . When the output transistor turns on with an inductive load the initial current through the load is 0 mA, and the transfer curve switches across to the left (V_{OL}) and slowly charges the inductor. When the output transistor turns off with an inductive load, the initial current is I_{OL} , which is sustained by the inductor and the transistor curve switches across to the right (V_B) through a high current and high voltage area which exceeds LV_{CEO} and instead of turning off (shown as dotted line) the device goes into secondary breakdown. It is generally not a good practice to let the output transistor's voltage exceed LV_{CEO} with an inductive load.

In a similar case with a capacitive load shown in Figure 4, the switching transfer characteristics rotate counter clockwise through the DC characteristics, unlike the inductive load which rotated clockwise. Even though the switching transfer curve exceeds LV_{CEO} , it didn't

go into secondary breakdown. Therefore, it is an acceptable practice to let the output transistor voltage exceed LVCEO, but not exceed BVCEO with a capacitive load.

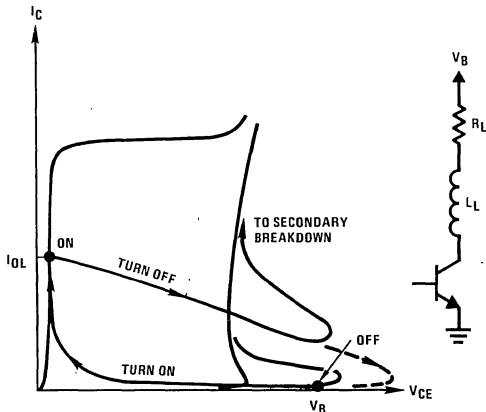


FIGURE 3. Inductive Load Transfer Characteristics

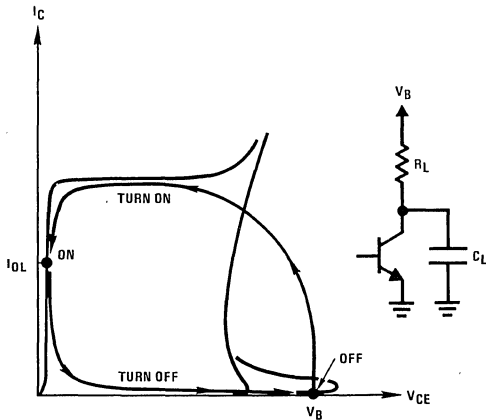


FIGURE 4. Capacitive Load Transfer Characteristics

Figure 5 shows an acceptable application with an inductive load. The load voltage (V_B) is less than LV_{CEO} , and the inductive voltage spike caused by the initial inductive current is quenched by a diode connected to V_B .

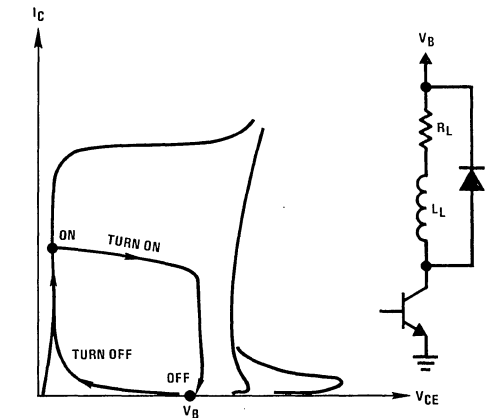


FIGURE 5. Inductive Load Transfer Characteristics Clamped by Diode

Figure 6 shows the switching transfer characteristics of a capacitive load which leads to secondary breakdown. This condition occurs due to high sustained currents, not breakdown voltage. In this example, the large capacitor prevented the output transistor from switching fast enough through the high current and high voltage region; in turn the power dissipation of the device was exceeded and the output transistor went into secondary breakdown.

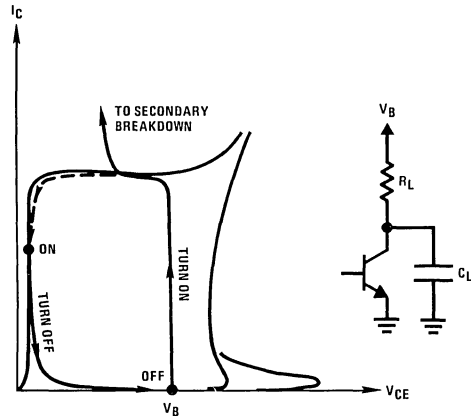


FIGURE 6. Capacitive Load Transfer Characteristics

Figure 7 shows another method of quenching the inductive voltage spike caused by the initial inductive current. This method dampens the switching response by the addition of R_D and C_D . The values of R_D and C_D are chosen to critically dampen the values of R_L and L_L ; this will limit the output voltage to $2 \times V_B$.

$$\frac{L_L}{(R_L + R_D)} \times \sqrt{\frac{1}{L_L C_D}} \leq 0.5$$

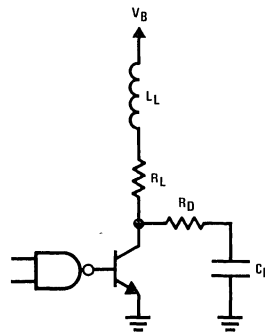


FIGURE 7. Inductive Load Dampened by Capacitor

Figure 8 shows a method of reducing high sustaining currents in a capacitive load. R_D in series with the capacitor (C_L) will limit the switching transistor without effecting final amplitude of the output voltage, since the IR drop across R_D will be zero after the capacitor is charged.

As an additional warning, beware of parasitic reactance. If the driver's load is located some distance from the driver (as an example: on the enclosure panel or through a connecting cable) there will be additional inductive and capacitance which may cause ringing on the driver

output which will exceed V_{CE0} or transient current that exceeds the sustaining current of the driver. A 300 mA current through a small inductor can cause a good size transient voltage, as compared with a 20 mA transient current observed with TTL gates. For no other reason than to reduce the noise associated with these transients, it is good practice to dampen the driver's output.

In conclusion, transient voltage associated with inductive loads can damage the peripheral driver, and transient currents associated with capacitive loads can also damage the driver. In some instances the device may not exhibit failure with the first switching cycle, but its conditions from ON to OFF will worsen after many cycles. In some cases the device will recover after the power has been turned off, but its long term reliability may have been degraded.

POWER DISSIPATION

Power Dissipation is limited by the IC Package Thermal Reactance and the external thermal reactance of the environment (PC board, heat sink, circulating air, etc.). Also, the power dissipation is limited by the maximum allowable junction temperature of the device. There are two contributions to the power: the internal

bias currents and voltage of the device, and the power on the output of the device due to the Driver Load.

POWER LIMITATIONS OF PACKAGE

Figure 9 shows the equivalent circuit of a typical power device in its application. Power is shown equivalent to electrical current, thermal resistance is shown equivalent to electrical resistance, the electrical reactance C and L are equivalent to the capacity to store heat, and the propagation delay through the medium. There are two mediums of heat transfer: conduction through mass and radiant convection. Convection is insignificant compared with conduction and isn't shown in the thermal resistance circuits. From the point power is generated (device junction) there are three possible paths to the ultimate heat sink: 1. through the device leads; 2. through the device surface by mechanical connection; and 3. through the device surface to ambient air. In all cases, the thermal paths are like delay lines and have a corresponding propagation delay. The thermal resistance is proportional to the length divided by the cross sectional area of the material. The Thermal Inductance is proportional to the length of the material (copper, molding compound, etc.) and inversely proportional to the cross sectional area. The thermal capacity is proportional to the volume of the material.

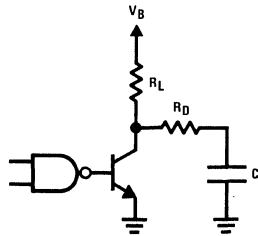


FIGURE 8. Capacitive Load with Current Limiting Resistor

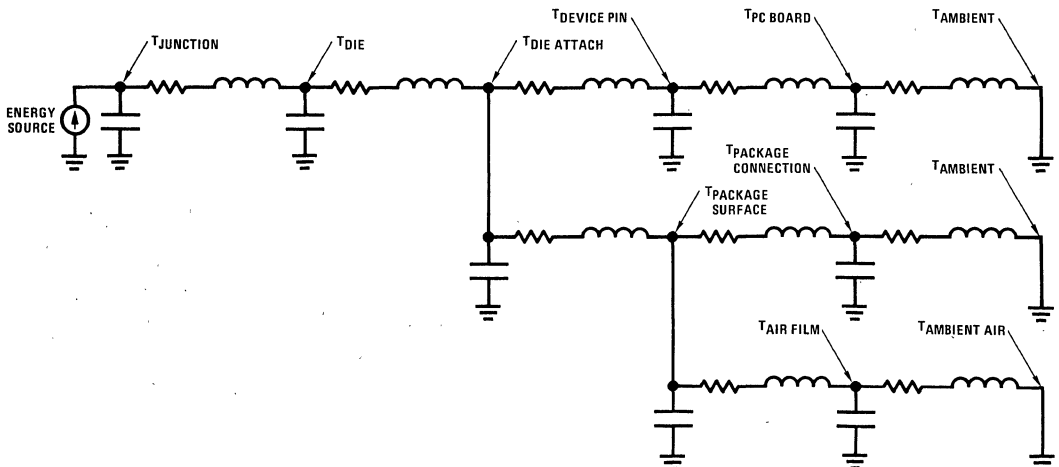


FIGURE 9. Thermal Reactance from Junction to Ambient

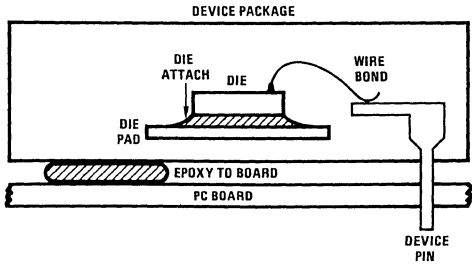


FIGURE 10. Components of Thermal Reactance for a Typical IC Package

National Semiconductor specifies the thermal resistance from device junction through the device leads soldered in a small PC board, measure in one cubic foot of still air. Figure 11 shows the maximum package power rating for an 8 pin Molded, an 8 pin Ceramic, 14 pin Molded and a 14 pin Ceramic package. The slope of the line corresponds to thermal resistance ($\phi_{JA} = \Delta P/\Delta T$).

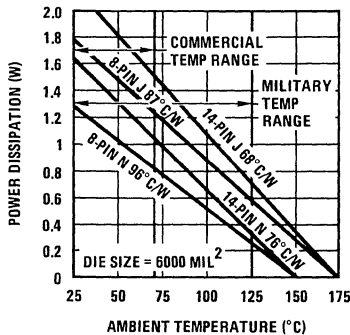


FIGURE 11. Maximum Package Power Rating

The maximum allowable junction temperature for ceramic packages is 175°C; operation above this temperature will reduce the reliability and life of the device below an acceptable level. At a temperature of 500°C the aluminum metallization paths on the die start to melt. The maximum allowable junction temperature for a molded device is 150°C, operations above this may cause the difference in thermal expansion between the molding compound and package lead frame to shear off the wire bonds from the die to the package lead. The industry standard for a molded device is 150°C, but National further recommends operation below 135°C if the device in its application will encounter a lot of thermal cycling (such as powered on and off over its life).

The way to determine the maximum allowable power dissipation from Figure 11, is to project a line from the maximum ambient temperature (T_A) of the application vertically (shown dotted in Figure 12), until

the line intercepts the diagonal line of the package type, and then project a line (shown dotted) horizontally until the line intercepts the Power Dissipation Axis (P_{MAX}).

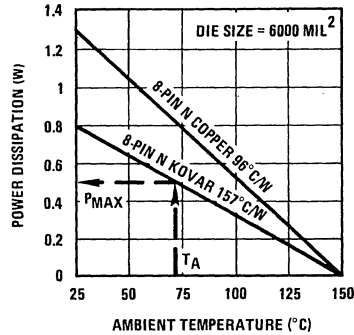


FIGURE 12. Maximum Package Rating Copper vs Kovar Lead Frame Packages

Figure 11 shows that 14 pin packages have less thermal resistance than 8 pin packages; which should be expected since it has more pins to conduct heat and has more surface area. Something that may not be expected is that the Thermal Resistance of the molded devices is comparable to the ceramic devices. The reason for the lower thermal resistance of the molded devices is the Copper lead frame, which is a better thermal conductor than the Kovar lead frame of the ceramic package. Almost all the peripheral drivers made by National Semiconductor are constructed with Copper lead frames (refer to ϕ_{JA} on the specific devices data sheet). The difference between the thermal resistance of Copper and Kovar in a molded package is shown in Figure 12.

Another variance in thermal resistance is the size of the IC die. If the contact area to the lead frame is greater, then the thermal resistance from the Die to the Lead Frame is reduced. This is shown in Figure 13. The thermal resistance shown in Figure 11 corresponds to die that are 6000 mil² in area.

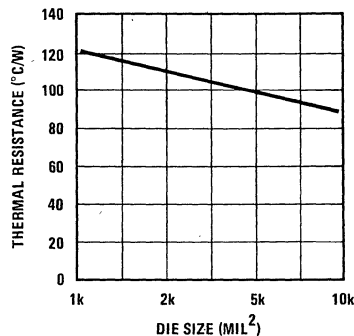


FIGURE 13. Thermal Resistance vs Die Size

In most applications the prime medium for heat conduction is through the device leads to the PC board, but the thermal resistance can be significantly improved by cooling air driven across the surface of the package. The conduction to air is limited by a stagnant film of air at the surface of the package. The film acts as an additional thermal resistance. The thickness of the film is proportional to its resistance. The thickness of the film is reduced by the velocity of the air across the package as shown in *Figure 14*. In most cases, the thermal resistance is reduced 25% at 250 linear feet/min, and 30% at 500 linear feet/min, above 500 linear feet/min the improvement flattens out.

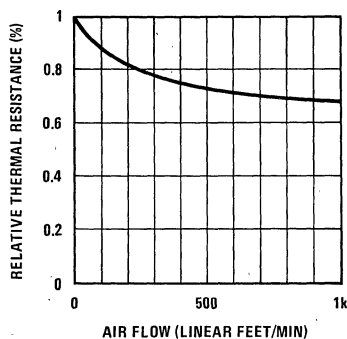


FIGURE 14. Thermal Resistance vs Air Velocity

The thermal resistance can also be improved by connecting the package to the PC board copper or by attaching metal wings to the package. The improvement by these means is outside the control of the IC manufacturer, but is available from the manufacture of the heat sink device. If the IC is mounted in a socket rather than soldered to a PC board, the thermal resistance through the device leads will worsen. In most cases, the thermal resistance is increased by 20%; again this is a variable subject to the specific socket type.

The maximum package rating shown in this note corresponds to a 90% confidence level that the package will have thermal resistance equal to or less than the value shown. The thermal resistance varies $\pm 5\%$ about the mean due to variables in assembly and package material.

CALCULATIONS OF POWER DISSIPATION

Most IC devices (such as T^2L) operate at power levels well below the device package rating, but peripheral drivers can easily be used at power levels that exceed the package rating unknowingly, if the power dissipation isn't calculated. As an example, the DS3654 Ten Bit Printer Driver could dissipate 3 watts (DC and, even more AC), and it is only in a 0.8 watt package. In this example, the device would be destroyed in moments, and may even burn a hole in the PC board it is mounted on. The DS3654 data sheet indicated that the 10 outputs could sink 300 mA with a Vol of 1 volt, but it wasn't intended that all the outputs would be

at the same time, and if so, not for a long period. The use of the DS3654 requires that the power be calculated vs the duty cycle of the outputs.

The DC power dissipation is pretty obvious, but in another example, a customer used the DS3686 relay driver to drive a 6.5 H inductive load. The DS3687 has an internal clamp network to quench the inductive back swing at 60V. At 5 Hz the device dissipates 2 watts, with transient peaks up to 11 watts. After 15 minutes of operation, the driver succumbs to thermal overload and becomes non-functional. The DS3687 was intended for telephone relay, which in most applications switches 20 times a day.

Peripheral driver will dissipate peak power levels that greatly exceed the average DC power. This is due to the capacity of the die and package to consume the transient energy while still maintaining the junction temperature at a safe level. This capacity is shown as a capacitor in *Figure 9*. In the lab (under a microscope) a device may be observed to glow orange around the parameter of the junction under excessive peak power without damage to the device. *Figure 15* shows a plot of maximum peak power vs applied time for the DS3654, and the same information plotted as energy vs applied time. To obtain these curves, the device leakage current when it switches off was used to monitor device limitation. Note in *Figure 15* there is a transition in the curve about 10 μs . At this point, the thermal capacity of the die has been exceeded. The thermal delay to the next thermal capacity (the package) was too long, and limited the peak power. These levels are not suggested operating levels, but an example of a Peripheral Driver to handle peak transient power.

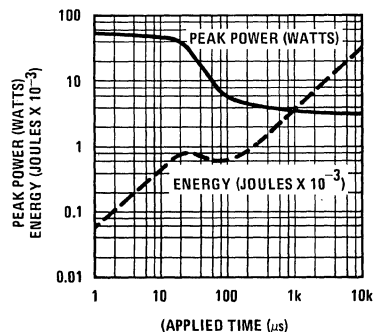


FIGURE 15. Peak Power and Energy vs the Period of Time the Power was Applied

To calculate power dissipation, the only information available to the design engineer is the parametric limits in the device data sheet, and the same information about the load reactance. If the calculations indicate the device is within its limits of power dissipation, then using those parametric limits is satisfactory. If the calculation of power dissipation is marginal, the parametric limits used in the calculations might be worst case at low temperature instead of high temperature

due to a positive temperature coefficient (T_C) of resistance. IC resistors and resistors associated with the load generally have a positive T_C . On the other hand, diodes and transistor emitter base voltages have a negative T_C ; which may in some circuits negate the effect of the resistors T_C . Peripheral output transistors have a positive T_C associated with V_{OL} ; while output Darlington transistors have a negative T_C at low currents and may be flat at high currents. *Figure 16* shows an example of power dissipation vs temperature; note that the power dissipation at the applications maximum temperature (T_A) was less than the power dissipation at lower temperatures. Since maximum junction temperature is the concern of the calculation, then maximum ambient temperature power should be used. The junction temperature may be determined by projecting a line (shown dotted in *Figure 16*), with a slope proportional to ϕ_{JA} back to the horizontal axis (shown as T_J). If the point is below the curve then T_J will be less than 150°C . T_J must not exceed the maximum junction temperature for that package type. In this example, T_J is less than 150°C as required by a molded package. To calculate the power vs temperature, it is necessary to characterize the device parameters vs temperature. Unfortunately, this information is not always provided by IC manufacturers in the device data sheets. A method to calculate I_{CC} vs temperature is to measure a device, then normalize the measurements vs the typical value for I_{CC} in the data sheet, then worst case the measurements by adding 30%. Thirty

percent is normally the worst-case resistor tolerance that IC devices are manufactured to.

CALCULATION OF OUTPUT POWER WITH AN INDUCTIVE LOAD

For this example, the device output circuit is similar to the DS3654 (10-Bit Printer Solenoid Driver) and the DS3686 and DS3687 (Telephone Relay Driver) as shown in *Figure 17*. Special features of the circuit type are the Darlington output transistors Q1 and Q2 and the zener diode from the collector of Q2 to the base of Q2. The Darlington output requires very little drive from the logic gate driving it and in turn dissipates less power when the output is turned ON and OFF, than a single saturating transistor output would. The zener diode (D_Z) quenches the inductive backswinging when the output is turned OFF.

Device and Load Characteristics Used for Power Calculation

VOL	Output Voltage ON	1.5V
VC	Output Clamp Voltage	65V
VB	Load Voltage	30V
RL	Load Resistance	120 Ω
LL	Load Inductance	5h
TON	Period ON	100 ms
TOFF	Period OFF	100 ms
T	Total Period	200 ms

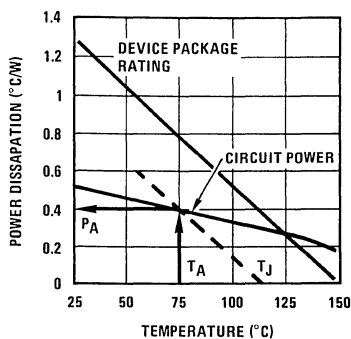


FIGURE 16. IC Power Dissipation vs Temperature

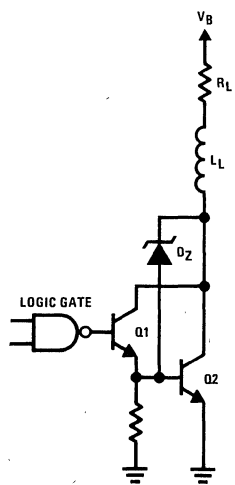


FIGURE 17. Peripheral Driver with Inductive Load

Refer to *Figure 18* voltage and current waveforms corresponding to the power dissipation calculated for this example of an inductive load.

P_{ON} = Average power dissipation in device output when device is ON during total period (T)

$$\tau = \frac{L_L}{R_L} = \frac{5h}{120 \Omega} = 41.7 \text{ ms}$$

$$I_L = \frac{V_B - V_{OL}}{R_L} = \frac{30 - 1.5}{120} = 237.5 \text{ mA}$$

$$I_p = I_L (1 - e^{-T_{ON}/\tau})$$

$$I_p = 237.5 \text{ mA} (1 - e^{-100 \text{ ms}/41.7 \text{ ms}})$$

$$I_p = 215.9 \text{ mA}$$

$$P_{ON} = V_{OL} \times I_L \times \frac{T_{ON}}{T} \left[1 - \int_0^{T_{ON}} \frac{e^{-t/\tau} dt}{T_{ON}} \right]$$

$$P_{ON} = V_{OL} \times I_L \times \frac{T_{ON}}{T} \left[1 - \frac{\tau}{T_{ON}} (1 - e^{-T_{ON}/\tau}) \right]$$

$$P_{ON} = 1.5 \times 237.5 \text{ mA} \times \frac{100}{200} \left[1 - \frac{41.7}{100} (1 - e^{-100/41.7}) \right]$$

$$P_{ON} = 110.6 \text{ mW}$$

P_{OFF} = Average power dissipation in device output when device is OFF during total period (T)

$$I_R = \frac{V_C - V_B}{R_L} = \frac{65 - 30}{120 \Omega} = 291.7 \text{ mA}$$

$$t_x = \tau \ln \left(\frac{I_L + I_R}{I_R} \right)$$

$$t_x = 41.7 \text{ ms} \ln \left(\frac{219.8 + 291.7}{291.7} \right) = 23.1 \text{ ms}$$

$$P_{OFF} = V_C \times \frac{t_x}{T} \left[(I_p + I_R) \times \frac{\tau}{t_x} (1 - e^{-t_x/\tau}) - I_R \right]$$

$$P_{OFF} = V_C \times \frac{t_x}{T} \left[(I_p + I_R) \times \frac{\tau}{t_x} (1 - e^{-t_x/\tau}) - I_R \right]$$

$$P_{OFF} = 65 \times \frac{23.1}{200} \left[(215.9 \text{ mA} + 291.7 \text{ mA}) \frac{41.7}{23.1} (1 - e^{-23.1/41.7}) - 291.7 \text{ mA} \right]$$

$$P_{OFF} = 736 \text{ mW}$$

P_O = Average power dissipation in device output

$$P_O = P_{ON} + P_{OFF} = 110.6 + 736 = 846.6 \text{ mW}$$

In the above example, driving a 120Ω inductive load at 5 Hz, the power dissipation exceeded a more simple calculation of power dissipation, which would have been:

$$P_O = \frac{V_{OL} (V_B - V_{OL})}{R_L} \times \frac{T_{ON}}{T}$$

$$P_O = \frac{1.5 (30 - 1.5)}{120} \times \frac{100 \text{ ms}}{200 \text{ ms}} = 182.5 \text{ mW}$$

An error 460% would have occurred by not including the reactive load. The total power dissipation must also include other outputs (if the device has more than one output), and the power dissipation due to the device power supply currents. This is an example where the load will most likely exceed the device package rating. If the load is fixed, the power can be reduced by changing the period (T) and duty rate (T_{ON}/T_{OFF}).

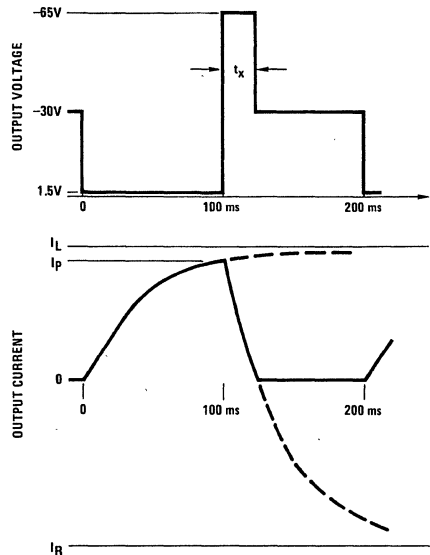


FIGURE 18. Voltage and Current Waveforms Corresponding to Inductive Load.

CALCULATION OF OUTPUT POWER WITH AN INCANDESCENT LAMP

An incandescent lamp is equivalent to a reactive load. The reactance is related to the period of time required to heat the lamp and the filaments positive temperature coefficient of resistance. *Figure 19* shows the transient response for a typical lamp used on instrument panels, and the equivalent electrical model for the lamp. Much like IC packages the lamp has a thermal circuit and its associated propagation delay. This lamp filament has an 8 ms time constant, and a longer 250 ms time constant from the lamp body to ambient. The DC characteristics are shown in *Figure 20*. Note the knee in the characteristics at 2 volts; this is where power starts to be dissipated in the form of light. This subject is important, since more peripheral drivers are damaged by lamps than any other load.

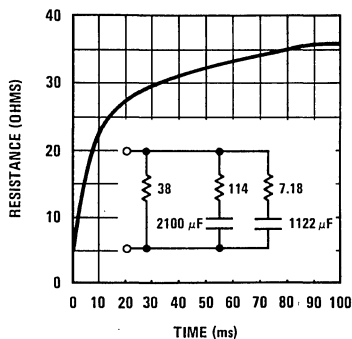


FIGURE 19. Transient Response of an Incandescent Lamp

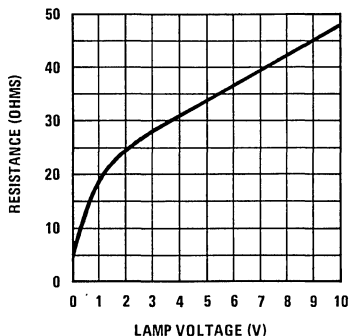


FIGURE 20. DC Characteristics of an Incandescent Lamp

Figure 21 shows the transient response of a driver similar to a DS75451 driving the lamp characterized in *Figures 19 and 20*. The equivalent load doesn't include the reactance of the lamp base to ambient, which has a 250 ms time constant, since 10 ms to an IC is equivalent to DC. The peak transient current was

1 amp, settling to 200 ms, with an 8 ms time constant. Observe the peak current is clamped at 1 amp, by the sinking ability of the driver; otherwise the peak current may have been 1.2 amps. The DS75451 is only rated at 300 mA, but it is reasonable to assume it could sink 1 amp because of the designed forced β required for switching response and worst case operating temperature.

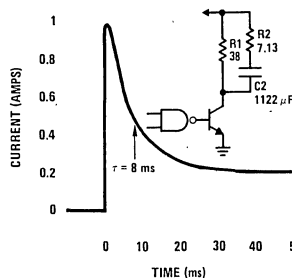


FIGURE 21. Transient Incandescent Lamp Current

Calculation of the energy dissipated by a peripheral driver for the transient lamp current shown in *Figure 21* is shown below, and the plot of energy vs time is shown in *Figure 22*. *Figure 22* also includes as a reference the maximum peak energy from *Figure 15*. It can be seen from *Figure 22* that in this example there is a good safety margin between the lamp load and the reference max peak energy. If there were more drivers than one per package under the same load, the margin would have been reduced. Also, if the peripheral driver couldn't saturate because it couldn't sink the peak transient lamp current, then the energy would also reduce the margin of safe operation.

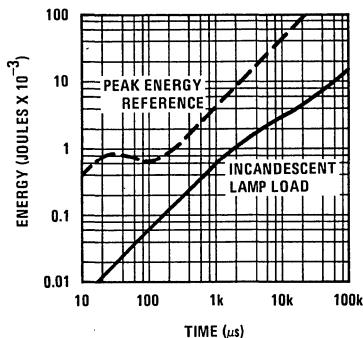


FIGURE 22. Energy vs Time for a Peripheral Driver with an Incandescent Lamp Load

CALCULATION OF ENERGY IN AN INCANDESCENT LAMP

$$\text{Energy} = \int_0^t V_{OL} (I_{R1} + I_{R2}) dt$$

$$i_{R1} = \frac{V_B - V_{OL}}{R1} = I_{R1}$$

$$i_{R2} = \left(\frac{V_B - V_{OL}}{R2} \right) e^{-t/\tau}$$

$$= I_{R2} e^{-t/\tau} \quad \tau = R2C2$$

$$\text{Energy} = \int_0^t V_{OL} (I_{R1} + I_{R2} e^{-t/\tau}) dt$$

$$= V_{OL} [I_{R1}t + I_{R2}\tau (1 - e^{-t/\tau})]$$

Given: $V_{OL} = 0.6V$
 $I_{R1} = 0.2 \text{ Amps}$
 $I_{R1} + I_{R2} = 1 \text{ Amp}$

A common technique used to reduce the 10 to 1 peak to DC transient lamp current is to bias the lamp partially ON, so the lamp filament is warm. This can be accomplished as shown in *Figure 23*. From *Figure 20* it can be seen that the lamp resistance at 0V is 5.7 Ω , but at 1V the resistance is 18 Ω . At 1V the lamp doesn't start to emit light. Using a lamp resistance of 100 Ω and lamp voltage of 1V, R_B was calculated to be approximately 100 Ω . This circuit will reduce the peak lamp current from 1 amp to 316 mA.

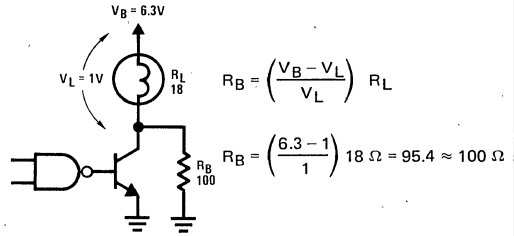


FIGURE 23. Circuit Used to Reduce Peak Transient Lamp Current

PERIPHERAL DRIVER SECTION

National Semiconductor has a wide selection of peripheral drivers as shown in the selection guide, *Figure 24*. The DS75451, DS75461, DS3631 and the DS3611 series have the same selection of logic function in an 8-pin package. The DS75461 is a high voltage selection of the DS75451 and may switch slower. The DS3611 and DS3631 are very high voltage circuits and were intended for slow relay applications. The DS3680, DS3686, and DS3687 were intended for 56V telephone relay applications. The DS3654 contains a 10-bit shift register followed by ten 250 mA clamped drivers. The DS3654 was intended for printer solenoid applications.

High current and high voltage peripheral drivers find many applications associated with digital systems, and it is the intention of the application note to insure that reliability and service life of peripheral drivers equal or exceed the performance of the other logic gates made by National.

For additional information, please contact Digital Interface Marketing Manager at National or one of the many field application engineers world wide.

Output High Voltage (V)	Latch-Up Voltage (Note 3) (V)	Output Low Voltage (V)	Output Low Current (mA)	Propagation Delay Typ (ns)	ON Power Supply Current (mA)	Drivers/Package	Input Compatibility (Logic)	Logic Function (Driver ON)	Device Number and Temperature Range	
									0°C to +70°C	-55°C to +125°C
30		0.5	100	40	152	8	TTL	Note 5	DP8310	DP7310
30		0.5	100	40	125	8	TTL	Note 6	DP8311	DP7311
20	13.5	0.6	100	70	90	2	TTL	Note 7	DS3616	
65	30	1.5	600		65	4	TTL/LS	NAND	DS3656	
70	35	0.7	600	2430	65	4	TTL/LS	NAND	DS3658	
70	Note 8	1.5	600	2000	80	4	TTL/LS	NAND	DS3668	
70	35	0.7	600		65	4	TTL/LS	AND	DS3669	
30	20	0.7	300	31	55	2	TTL	AND	DS75450	
30	20	0.7	300	31	55	2	TTL	AND	DS75451	DS55451
30	20	0.7	300	31	55	2	TTL	NAND	DS75452	DS55452
30	20	0.7	300	31	55	2	TTL	OR	DS75453	DS55453
30	20	0.7	300	31	55	2	TTL	NOR	DS75454	DS55454
35	30	0.7	300	33	55	2	TTL	AND	DS75461	DS55461
35	30	0.7	300	33	55	2	TTL	NAND	DS75462	DS55462
35	30	0.7	300	33	55	2	TTL	OR	DS75463	DS55463
35	30	0.7	300	33	55	2	TTL	NOR	DS75464	DS55464
56	40	1.4	300	150	8	2	CMOS	AND	DS3631	DS1631
56	40	1.4	300	150	8	2	CMOS	NAND	DS3632	DS1632
56	40	1.4	300	150	8	2	CMOS	OR	DS3633	DS1633
56	40	1.4	300	150	8	2	CMOS	NOR	DS3634	DS1634
80	50	0.7	300	125	75	2	TTL/CMOS	AND	DS3611	DS1611
80	50	0.7	300	125	75	2	TTL/CMOS	NAND	DS3612	DS1612
80	50	0.7	300	125	75	2	TTL/CMOS	OR	DS3613	DS1613
80	50	0.7	300	125	75	2	TTL/CMOS	NOR	DS3614	DS1614
-2.1	-60	-60	-50	10,000	4.4	4	TTL/CMOS	(Note 4)	DS3680	
(Note 1)	56	1.3	300	1000	28	2	TTL/CMOS	NAND	DS3686	
(Note 1)	-56	-1.3	300	1000	28	2	TTL/CMOS	NAND	DS3687	DS1687
13.5	15	V _{CC} -1.8	300	150	0.015	2	CMOS	AND	MM74C908, MM74C918	
(Note 1)	45	1.6	250	1000	70	10	(Note 2)	(Note 2)	DS3654	

Note 1: The DS3686, DS3687 and DS3654 contain an internal inductive fly-back clamp circuit connected from the output to ground. As an example, DS3686 driving a relay solenoid connected to 28V would clamp the output voltage fly-back transient at 56V caused by the solenoid's stored inductive current. This clamp protects the circuit output and quenches the fly-back.

Note 2: The DS3654 is a 10-bit shift register followed by 10 enabled drivers. The input circuit is equivalent to a 4k resistor to ground, and the logic input thresholds are 2.8V and 0.8V. The recommended power supply voltage is 7.5V to 9.5V. The circuit can be cascaded to be a 20 or 30-bit shift register.

Note 3: Latch-up voltage is the maximum voltage the output can sustain when switching an inductive load.

Note 4: DS3680 has a differential input circuit.

Note 5: DP8310 inverting, positive edge latching.

Note 6: DP8311 inverting, fall through latch.

Note 7: Bubble memory coil driver.

Note 8: DS3668 35V, latch-up with output fault protection.

FIGURE 24. Peripheral/Power Driver Selection Guide



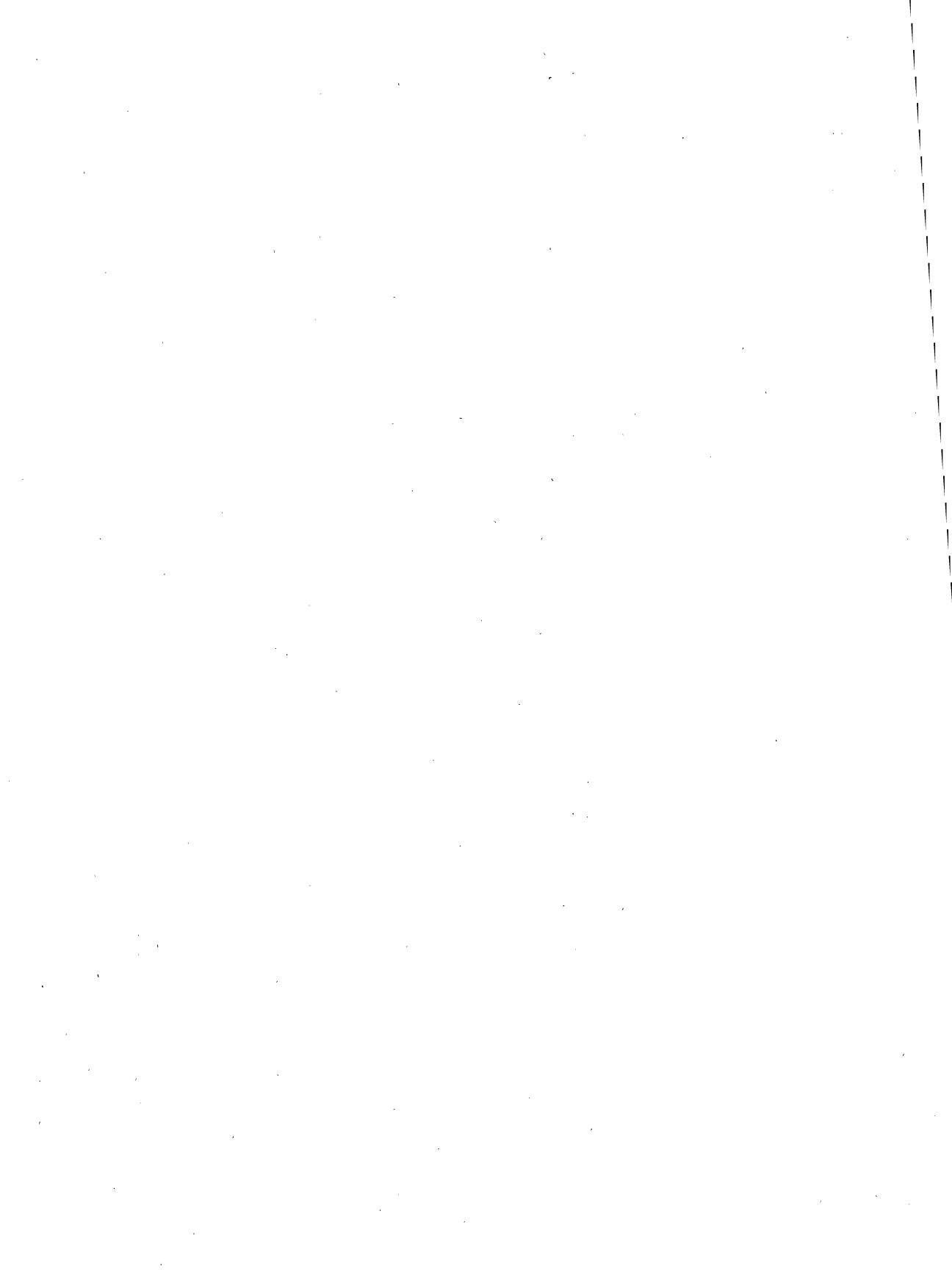


Section 4 Level Translators/ Buffers

4

TEMPERATURE RANGE		DESCRIPTION	PAGE NUMBER
-55°C to +125°C	0°C to +70°C		
—	DP8480	10k ECL to TTL Level Translator with Latch	4-4
—	DP8481	TTL to 10k ECL Level Translator with Latch	4-7
—	DP8482	100k ECL to TTL Level Translator with Latch	4-10
—	DP8483	TTL to 100k Level Translator with Latch	4-13
DS1630	DS3630	Hex CMOS Compatible Buffer	4-16
*DS7800	DS8800	Dual Voltage Level Translator	4-19
*DS7810	DS8810	Quad 2-Input TTL-to-MOS Interface Gate	4-22
*DS7811	DS8811	Quad 2-Input TTL-to-MOS Interface Gate	4-22
*DS7812	DS8812	Hex TTL-to-MOS Inverter	4-22
*DS78L12	DS88L12	Hex TTL-to-MOS Inverter/Interface Gate	4-25
*DS7819	DS8819	Quad 2-Input TTL-to-MOS Gate	4-27
MM54C901	MM74C901	Hex Inverting TTL Buffer	CMOS
MM54C902	MM74C902	Hex Non-Inverting TTL Buffer	CMOS
MM54C903	MM74C903	Hex Inverting PMOS Buffer	CMOS
MM54C904	MM74C904	Hex Non-Inverting PMOS Buffer	CMOS
MM54C906	MM74C906	Hex Open Drain N-Channel Buffer	CMOS
MM54C907	MM74C907	Hex Open Drain P-Channel Buffer	CMOS

* Also available screened in accordance with MIL-STD-883 Class B. Refer to National Semiconductor's "The Reliability Handbook".



LEVEL TRANSLATORS/BUFFERS

INPUT	OUTPUT	OUTPUT CHARACTERISTICS	LOGIC FUNCTION	DEVICE NUMBER		Page No.
				0°C to +70°C	-55°C to +125°C	
10k ECL	TTL	TRI-STATE [®] Fall Through Latch	Inverting	DP8480		4-4
TTL	10k ECL	Gated Fall Through Latch	Inverting	DP8481		4-7
100k ECL	TTL	TRI-STATE Fall Through Latch	Inverting	DP8482		4-10
TTL	100k ECL	Gated Fall Through Latch	Inverting	DP8483		4-13
CMOS	CMOS	50 ns Prop. Delay at 500 pF	Hex Buffer	DS3630	DS1630	4-16
TTL	PMOS	Open-Collector -30V to 30V	Dual 2-Input Gate	DS8800	DS7800	4-19
TTL	MOS	Open-Collector 0.4V to 14V	Quad 2-Input Gate	DS8810	DS7810	4-22
TTL	MOS	Open-Collector 0.4V to 14V	Quad 2-Input Gate	DS8811	DS7811	4-22
TTL	MOS	Open-Collector 0.4V to 14V	Hex Inverter	DS8812	DS7812	4-22
TTL	MOS	Active Pull-Up 0.4V to 14V	Hex Inverter	DS88L12	DS78L12	4-25
TTL	MOS	Open-Collector 0.4V to 14V	Quad 2-Input Gate	DS8819	DS7819	4-27
CMOS	TTL	Active Pull-Up 0.4V @ 2.6 mA	Hex Inverter	MM74C901	MM54C901	CMOS
CMOS	TTL	Active Pull-Up 0.4V @ 3.2 mA	Hex Buffer	MM74C902	MM54C902	CMOS
CMOS	PMOS	Active Pull-Up 0V to 15V	Hex Inverter	MM74C903	MM54C903	CMOS
CMOS	PMOS	Active Pull-Up 0V to 15V	Hex Buffer	MM74C904	MM54C904	CMOS
CMOS	NMOS	Open Drain 0V to 15V	Hex Buffer	MM74C906	MM54C906	CMOS
CMOS	PMOS	Open Drain V_{CC} to $V_{CC} - 15V$	Hex Buffer	MM74C907	MM54C907	CMOS

DP8480 10k ECL to TTL Level Translator with Latch

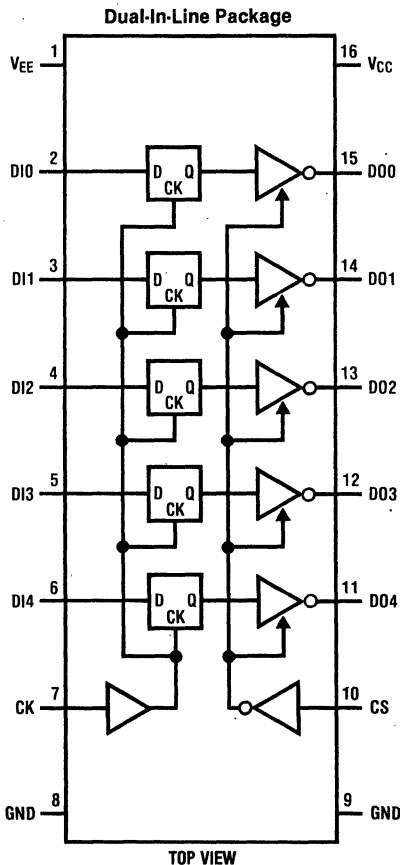
General Description

This circuit translates ECL input levels to TTL output levels and provides a fall-through latch. The TRI-STATE® outputs are designed to drive large capacitive loads. The clock and chip select inputs are ECL.

Features

- 16-pin flat-pack or DIP
- TRI-STATE outputs
- ECL control inputs
- 5.5 ns typical propagation delay with 50 pF load
- Outputs are TRI-STATE during power up/down for glitch free operation
- 10k ECL input compatible

Logic and Connection Diagram



Truth Table

DI	DO	CK	CS
H	L	L	L
L	H	L	L
X	DO	H	L
X	Hi-Z	X	H

H = high level (most positive)
L = low level (most negative)
X = don't care

Order Number DP8480N or DP8480F
See NS Package N16A or F16B

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Absolute Maximum Ratings (Note 1)

V_{EE} Supply Voltage	-8V
V_{CC} Supply Voltage	7V
Input Voltage	GND to V_{EE}
Output Voltage	5.5V
Maximum Power Dissipation* at 25°C	
Molded Package	1476 mW
Storage Temperature	-65°C to 150°C

* Derate molded package 11.8 mW/°C above 25°C.

Recommended Operating Conditions

V_{EE} Supply Voltage	-5.2V ± 10%
V_{CC} Supply Voltage	5.0V ± 10%
T_A , Ambient Temperature	0°C to 75°C

Electrical Characteristics (TTL Logic) Notes 2, 3 and 4

Parameter	Conditions	Min	Typ	Max	Units
V_{OL} Output Low Voltage	$I_{OL} = 8$ mA			0.5	V
V_{OH} Output High Voltage	$I_{OH} = -1$ mA	2.5			V
I_{OD} Output Low Drive Current	Force 5V with Output Low		150		mA
I_{1D} Output High Drive Current	Force 0V with Output High		-150		mA
I_{OZ} TRI-STATE Output Current			1		μA
I_{CC} Supply Current				62.5	mA

Electrical Characteristics (ECL Logic) Notes 2 and 3

Parameter	Conditions	T_A	Min	Typ	Max	Units
V_{IL} Input Low Voltage	$V_{EE} = -5.2$ V	0°C 25°C 75°C	-1870 -1850 -1830		-1490 -1475 -1450	mV
V_{IH} Input High Voltage	$V_{EE} = -5.2$ V	0°C 25°C 75°C	-1145 -1105 -1045		-840 -810 -720	mV
I_{IL} Input Low Current				0.5		μA
I_{IH} Input High Current				350		μA
I_{EE} Supply Current					-50	mA

Switching Characteristics Notes 2 and 5

Parameter	Conditions	Min	Typ	Max	Units
t_{CDOL} Clock to Data Out Low Delay	$C_L = 50$ pF		6.75	11.5	ns
t_{CDOH} Clock to Data Out High Delay	$C_L = 50$ pF		6.75	11.5	ns
t_{DIDOH} Data In to Data Out High Delay	$C_L = 50$ pF		5.5	9.5	ns
t_{DIDOL} Data In to Data Out Low Delay	$C_L = 50$ pF		5.5	9.5	ns
t_S Data Set-Up Time	$C_L = 50$ pF	3.0	1.0		ns
t_H Data Hold Time	$C_L = 50$ pF	3.0	1.0		ns
t_{CPW} Clock Pulse Width	$C_L = 50$ pF	5.0	3.0		ns
t_{ZE} Delay from Chip Select to Active State from Hi-Z State	$C_L = 50$ pF		8		ns
t_{EZ} Delay from Chip Select to Hi-Z State from Active State	$C_L = 50$ pF		8		ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

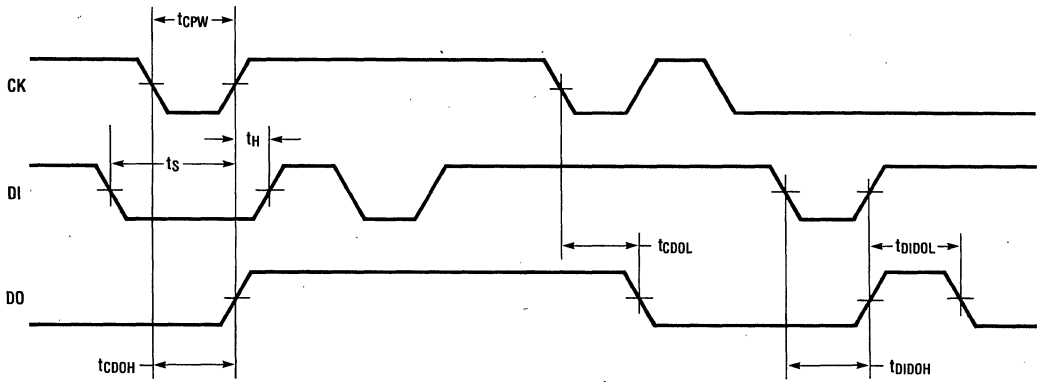
Note 2: Unless otherwise specified, min/max limits apply across the 0°C to 75°C ambient temperature range in still air and across the specified supply variations. All typical values are for $T_A = 25^\circ\text{C}$ and nominal supply.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative. All voltages are referenced to ground, unless otherwise specified.

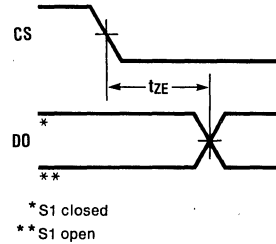
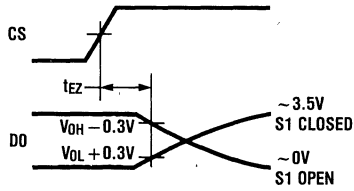
Note 4: When DC testing I_{1D} or I_{OD} a 15Ω resistor should be in series with the output. Only one output should be tested at a time.

Note 5: Unless otherwise specified, all AC measurements are referenced from the 50% level of the ECL input to the 0.8V level on negative transitions or the 2.4V level on positive transitions of the output. ECL input rise and fall times are 2.0 ns ± 0.2 ns from 20% to 80%.

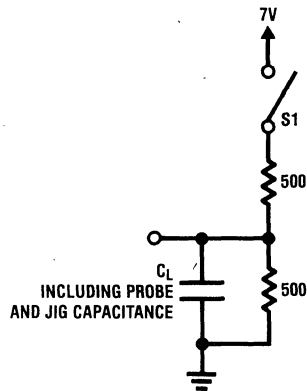
Switching Time Waveforms



S1 open



Test Load



DP8481 TTL to 10k ECL Level Translator with Latch

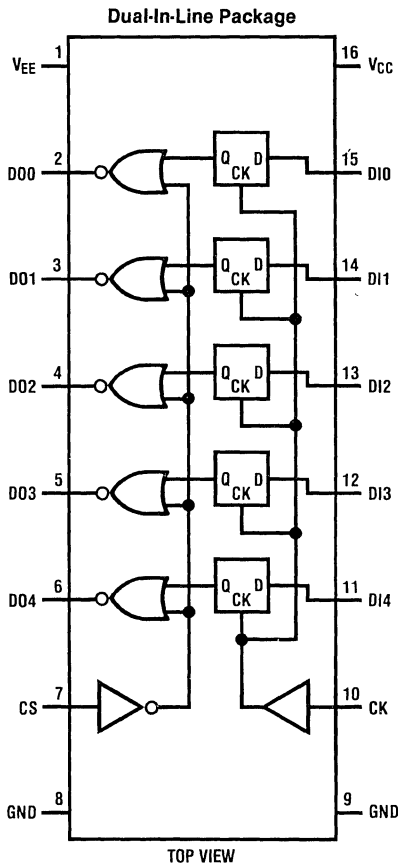
General Description

This circuit translates TTL input levels to ECL output levels and provides a fall-through latch. The outputs are gated with CS providing for wire ORing of outputs. The clock and chip select inputs are ECL.

Features

- 16-pin flat-pack or DIP
- ECL control inputs
- CS provided for wire ORing of output bus
- 10k ECL I/O compatible
- 4.0 ns typical propagation delay

Logic and Connection Diagram



Truth Table

DI	DO	CK	CS
H	L	L	H
L	H	L	H
X	DO	H	H
X	L	X	L

H = high level (most positive)
L = low level (most negative)
X = don't care

Order Number DP8481N or DP8481F
See NS Package N16A or F16B

Absolute Maximum Ratings (Note 1)

V_{EE} Supply Voltage	-8V
V_{CC} Supply Voltage	7V
Input Voltage (ECL)	GND to V_{EE}
Input Voltage (TTL)	-1V to 5.5V
Output Current	50 mA
Maximum Power Dissipation* at 25°C	
Molded Package	1476 mW
Storage Temperature	-65°C to +150°C

*Derate molded package 11.8 mW/°C above 25°C.

Recommended Operating Conditions

V_{EE} Supply Voltage	-5.2V ± 10%
V_{CC} Supply Voltage	5.0V ± 10%
T_A , Ambient Temperature	0°C to 75°C

Electrical Characteristics (TTL Logic) Notes 2 and 3

Parameter	Conditions	Min	Typ	Max	Units
V_{IL} Input Low Voltage				0.8	V
V_{IH} Input High Voltage		2.0			V
I_{IL} Input Low Current	$V_{IN} = 0.5V$		-50		μA
I_{IH} Input High Current	$V_{IN} = 2.5V$		1.0		μA
V_{CLAMP} Input Clamp Voltage	$I_{IN} = -12 mA$		-0.8		V
I_{CC} Supply Current				30	mA

Electrical Characteristics (ECL Logic) Notes 2 and 3

Parameter	Conditions	T_A	Min	Typ	Max	Units
V_{IL} Input Low Voltage	$V_{EE} = -5.2V$	0°C	-1870		-1490	mV
		25°C	-1850		-1475	
		75°C	-1830		-1450	
V_{IH} Input High Voltage	$V_{EE} = -5.2V$	0°C	-1145		-840	mV
		25°C	-1105		-810	
		75°C	-1045		-720	
I_{IL} Input Low Current				0.5		μA
I_{IH} Input High Current				350		μA
V_{OL} Output Low Voltage	$V_{EE} = -5.2V$	0°C	-1870		-1665	mV
		25°C	-1850		-1650	
		75°C	-1830		-1625	
V_{OH} Output High Voltage	$V_{EE} = -5.2V$	0°C	-1000		-840	mV
		25°C	-960		-810	
		75°C	-900		-720	
V_{OLC} Output Low Voltage	$V_{EE} = -5.2V$	0°C			-1645	mV
		25°C			-1630	
		75°C			-1605	
V_{OHC} Output High Voltage	$V_{EE} = -5.2V$	0°C	-1020			mV
		25°C	-980			
		75°C	-920			
I_{EE} Supply Current					-90	mA

Switching Characteristics Notes 2 and 4

Parameter	Conditions	Min	Typ	Max	Units
t_{CDOL}	Clock to Data Out Low Delay		4.0	6.5	ns
t_{CDOH}	Clock to Data Out High Delay		4.0	6.5	ns
t_{DIDOH}	Data In to Data Out High Delay		4.0	6.5	ns
t_{DIDOL}	Data In to Data Out Low Delay		4.0	6.5	ns
t_S	Data Set-Up Time to Clock	3.0	1.0		ns
t_H	Data Hold Time	3.0	1.0		ns
t_{CPW}	Clock Pulse Width	5.0	3.0		ns
t_{CSDOH}	Chip Select to Data Out High Delay		3.0	4.5	ns
t_{CSDOL}	Chip Select to Data Out Low Delay		3.0	4.5	ns
t_{SCS}	Data Set-Up Time to Chip Select	5.5	3.0		ns

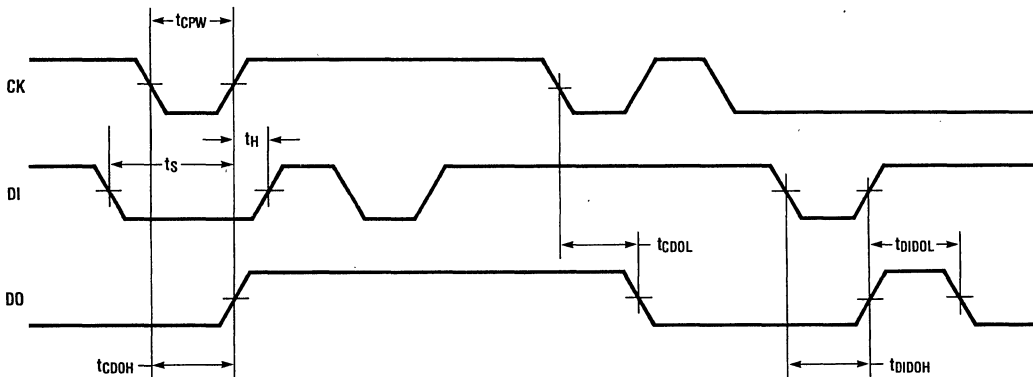
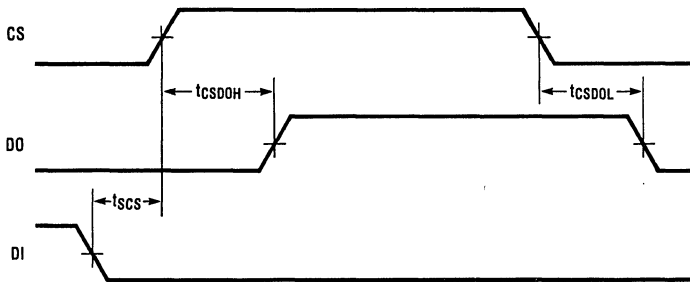
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to 75°C ambient temperature range in still air and across the specified supply variations. All typical values are for 25°C and nominal supply.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative. All voltages are referenced to ground, unless otherwise specified.

Note 4: Unless otherwise specified, all AC measurements are referenced from the 1.5V level of the TTL input and to/from the 50% point of the ECL signal and a 50Ω resistor to -2V is the load. ECL input rise and fall times are 2.0 ns ± 0.2 ns from 20% to 80%. TTL input characteristic is 0V to 3V with $t_r = t_f \leq 3$ ns measured from 10% to 90%.

Switching Time Waveforms



DP8482 100k ECL to TTL Level Translator with Latch

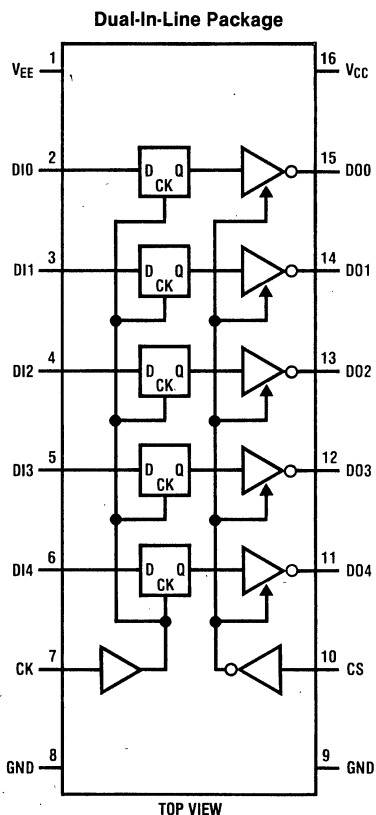
General Description

This circuit translates ECL input levels to TTL output levels and provides a fall-through latch. The TRI-STATE® outputs are designed to drive large capacitive loads. The clock and chip select inputs are ECL.

Features

- 16-pin flat-pack or DIP
- TRI-STATE outputs
- ECL control inputs
- 5.5 ns typical propagation delay with 50 pF load
- Outputs are TRI-STATE during power up/down for glitch free operation
- 100k ECL input compatible

Logic and Connection Diagram



Truth Table

DI	DO	CK	CS
H	L	L	L
L	H	L	L
X	DO	H	L
X	Hi-Z	X	H

H = high level (most positive)
L = low level (most negative)
X = don't care

Order Number DP8482N or DP8482F
See NS Package N16A or F16B

Absolute Maximum Ratings (Note 1)

V_{EE} Supply Voltage	-8V
V_{CC} Supply Voltage	7V
Input Voltage	GND to V_{EE}
Output Voltage	5.5V
Maximum Power Dissipation* at 25°C	
Molded Package	1476 mW
Storage Temperature	-65°C to +150°C

* Derate molded package 11.8 mW/°C above 25°C.

Recommended Operating Conditions

V_{EE} Supply Voltage	-4.5V ± 7%
V_{CC} Supply Voltage	5.0V ± 10%
T_A , Ambient Temperature	0°C to 85°C

Electrical Characteristics (TTL Logic) Notes 2, 3 and 4

Parameter	Conditions	Min	Typ	Max	Units
V_{OL} Output Low Voltage	$I_{OL} = 8$ mA			0.5	V
V_{OH} Output High Voltage	$I_{OH} = -1$ mA	2.5			V
I_{OD} Output Low Drive Current	Force 5V with Output Low		150		mA
I_{ID} Output High Drive Current	Force 0V with Output High		-150		mA
I_{OZ} TRI-STATE Output Current			1		μA
I_{CC} Supply Current				62.5	mA

Electrical Characteristics (ECL Logic) Notes 2 and 3

Parameter	Conditions	T_A	Min	Typ	Max	Units
V_{IL} Input Low Voltage	$V_{EE} = -4.5$ V		-1810		-1475	mV
V_{IH} Input High Voltage	$V_{EE} = -4.5$ V		-1165		-880	mV
I_{IL} Input Low Current				0.5		μA
I_{IH} Input High Current				350		μA
I_{EE} Supply Current					-50	mA

Switching Characteristics Notes 2 and 5

Parameter	Conditions	Min	Typ	Max	Units
t_{CDOL} Clock to Data Out Low Delay	$C_L = 50$ pF		6.75	11.5	ns
t_{CDOH} Clock to Data Out High Delay	$C_L = 50$ pF		6.75	11.5	ns
t_{DIDOH} Data In to Data Out High Delay	$C_L = 50$ pF		5.5	9.5	ns
t_{DIDOL} Data In to Data Out Low Delay	$C_L = 50$ pF		5.5	9.5	ns
t_S Data Set-Up Time	$C_L = 50$ pF	3.0	1.0		ns
t_H Data Hold Time	$C_L = 50$ pF	3.0	1.0		ns
t_{CPW} Clock Pulse Width	$C_L = 50$ pF	5.0	3.0		ns
t_{ZE} Delay from Chip Select to Active State from Hi-Z State	$C_L = 50$ pF		8		ns
t_{EZ} Delay from Chip Select to Hi-Z State from Active State	$C_L = 50$ pF		8		ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

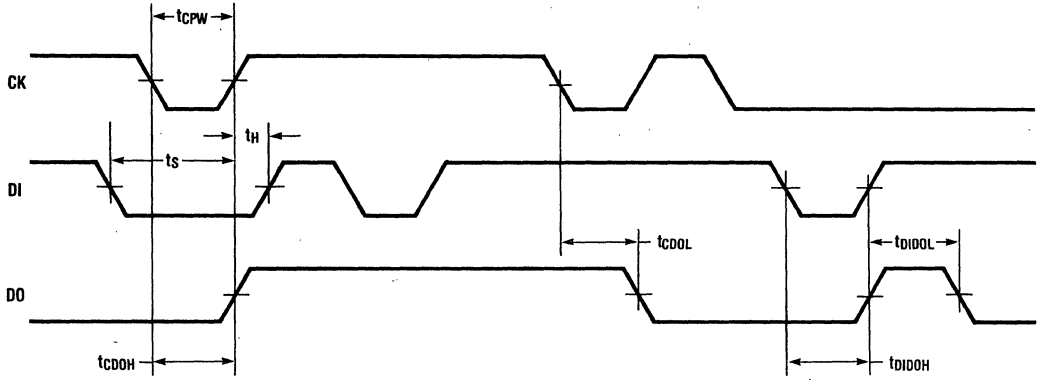
Note 2: Unless otherwise specified, min/max limits apply across the 0°C to 85°C ambient temperature range in still air and across the specified supply variations. All typical values are for $T_A = 25$ °C and nominal supply.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative. All voltages are referenced to ground, unless otherwise specified.

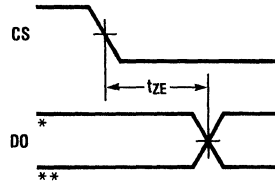
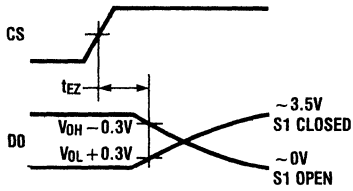
Note 4: When DC testing I_{ID} or I_{OD} a 15Ω resistor should be in series with the output. Only one output should be tested at a time.

Note 5: Unless otherwise specified, all AC measurements are referenced from the 50% level of the ECL input to the 0.8V level on negative transitions or the 2.4V level on positive transitions of the output. ECL input rise and fall times are 0.7 ns ± 0.1 ns from 20% to 80%.

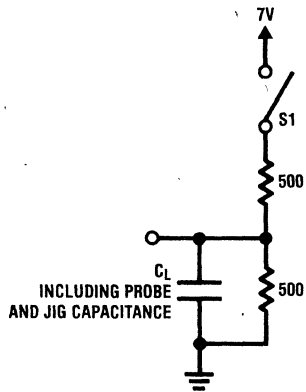
Switching Time Waveforms



S1 open



Test Load



DP8483 TTL to 100k ECL Level Translator with Latch

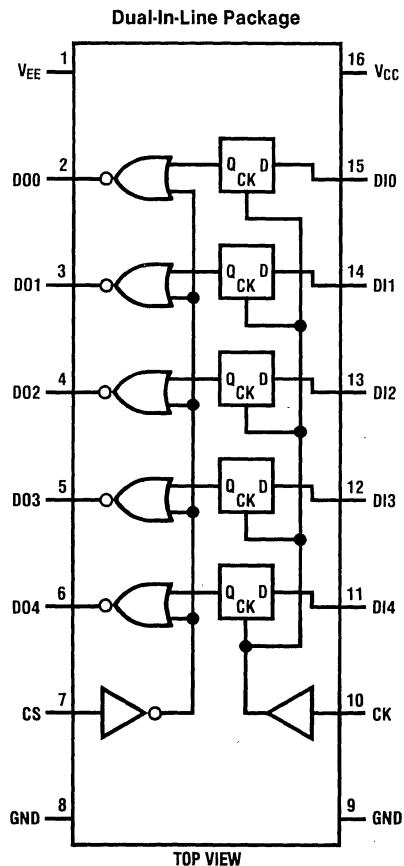
General Description

This circuit translates TTL input levels to ECL output levels and provides a fall-through latch. The outputs are gated with CS providing for wire ORing of outputs. The clock and chip select inputs are ECL.

Features

- 16-pin flat-pack or DIP
- ECL control inputs
- CS provided for wire ORing of output bus
- 100k ECL I/O compatible
- 4.0 ns typical propagation delay

Logic and Connection Diagram



Truth Table

DI	DO	CK	CS
H	L	L	H
L	H	L	H
X	DO	H	H
X	L	X	L

H = high level (most positive)

L = low level (most negative)

X = don't care

Order Number DP8483N or DP8483F
 See NS Package N16A or F16B

Absolute Maximum Ratings (Note 1)

V_{EE} Supply Voltage	- 8V
V_{CC} Supply Voltage	7V
Input Voltage (ECL)	GND to V_{EE}
Input Voltage (TTL)	- 1V to 5.5V
Output Current	50 mA
Maximum Power Dissipation* at 25°C	
Molded Package	1476 mW
Storage Temperature	- 65°C to + 150°C

*Derate molded package 11.8 mW/°C above 25°C.

Recommended Operating Conditions

V_{EE} Supply Voltage	- 4.5V ± 7%
V_{CC} Supply Voltage	5.0V ± 10%
T_A , Ambient Temperature	0°C to 85°C

Electrical Characteristics (TTL Logic) Notes 2 and 3

Parameter	Conditions	Min	Typ	Max	Units
V_{IL} Input Low Voltage				0.8	V
V_{IH} Input High Voltage		2.0			V
I_{IL} Input Low Current	$V_{IN} = 0.5V$		- 50		μA
I_{IH} Input High Current	$V_{IN} = 2.5V$		1.0		μA
V_{CLAMP} Input Clamp Voltage	$I_{IN} = -12 mA$		- 0.8		V
I_{CC} Supply Current				30	mA

Electrical Characteristics (ECL Logic) Notes 2 and 3

Parameter	Conditions	T_A	Min	Typ	Max	Units
V_{IL} Input Low Voltage	$V_{EE} = -4.5V$		- 1810		- 1475	mV
V_{IH} Input High Voltage	$V_{EE} = -4.5V$		- 1165		- 880	mV
I_{IL} Input Low Current				0.5		μA
I_{IH} Input High Current				350		μA
V_{OL} Output Low Voltage	$V_{EE} = -4.5V$		- 1810	- 1705	- 1620	mV
V_{OH} Output High Voltage	$V_{EE} = -4.5V$		- 1025	- 955	- 880	mV
V_{OLC} Output Low Voltage	$V_{EE} = -4.5V$				- 1610	mV
V_{OHC} Output High Voltage	$V_{EE} = -4.5V$		- 1035			mV
I_{EE} Supply Current					- 90	mA

Switching Characteristics Notes 2 and 4

Parameter	Conditions	Min	Typ	Max	Units
t_{CDOL}	Clock to Data Out Low Delay		4.0	6.5	ns
t_{CDOH}	Clock to Data Out High Delay		4.0	6.5	ns
t_{DIDOH}	Data In to Data Out High Delay		4.0	6.5	ns
t_{DIDOL}	Data In to Data Out Low Delay		4.0	6.5	ns
t_s	Data Set-Up Time to Clock	3.0	1.0		ns
t_H	Data Hold Time	3.0	1.0		ns
t_{CPW}	Clock Pulse Width	5.0	3.0		ns
t_{CSDOH}	Chip Select to Data Out High Delay		3.0	4.5	ns
t_{CSDOL}	Chip Select to Data Out Low Delay		3.0	4.5	ns
t_{SCS}	Data Set-Up Time to Chip Select	5.5	3.0		ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

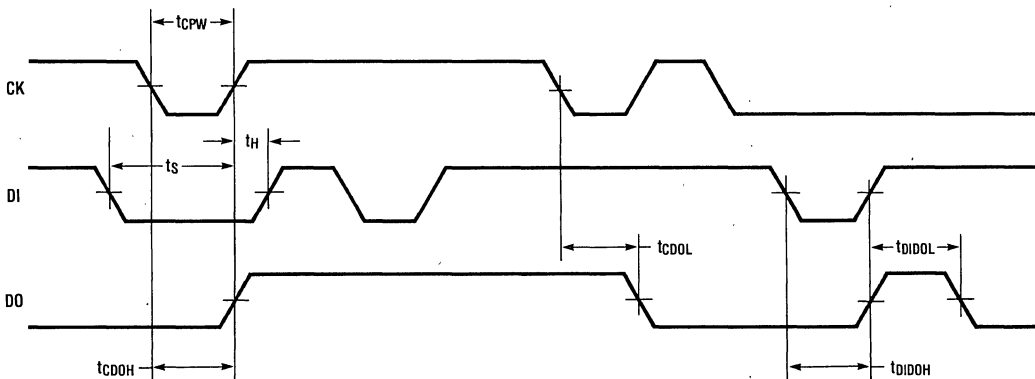
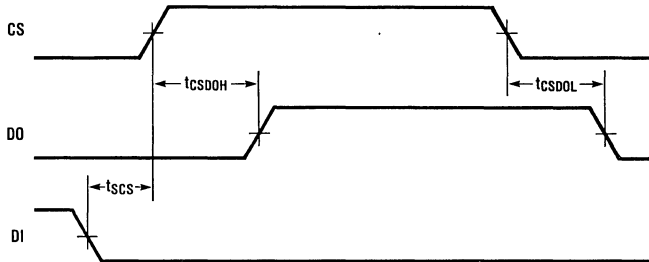
Note 2: Unless otherwise specified, min/max limits apply across the 0°C to 85°C ambient temperature range in still air and across the specified supply variations. All typical values are for 25°C and nominal supply.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative. All voltages are referenced to ground, unless otherwise specified.

Note 4: Unless otherwise specified, all AC measurements are referenced from the 1.5V level of the TTL input and to/from the 50% point of the ECL signal and a 50Ω resistor to -2V is the load. ECL input rise and fall times are 0.7 ns ± 0.1 ns from 20% to 80%. TTL input characteristic is 0V to 3V with $t_r = t_f \leq 3$ ns measured from 10% to 90%.

4

Switching Time Waveforms



DS1630/DS3630 Hex CMOS Compatible Buffer

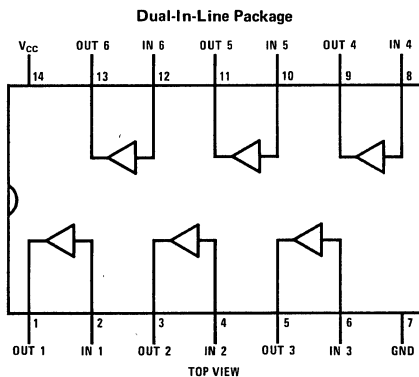
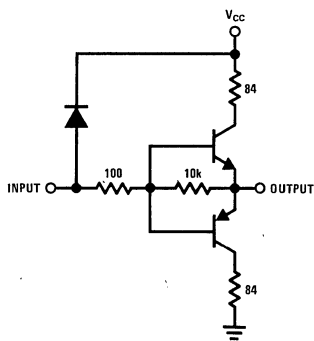
General Description

The DS1630/DS3630 is a high current buffer intended for use with CMOS circuits interfacing with peripherals requiring high drive currents. The DS1630/DS3630 features low quiescent power consumption (typically $50\mu W$) as well as high-speed driving of capacitive loads such as large MOS memories. The design of the DS1630/DS3630 is such that V_{CC} current spikes commonly found in standard CMOS circuits cannot occur, thereby, reducing the total transient and average power when operating at high frequencies.

Features

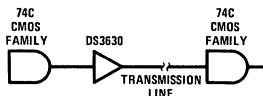
- High-speed capacitive driver
- Wide supply voltage range
- Input/output may interface to TTL
- Input/output CMOS compatibility
- No internal transient V_{CC} current spikes
- $50\mu W$ typical standby power

Equivalent Schematic and Connection Diagrams

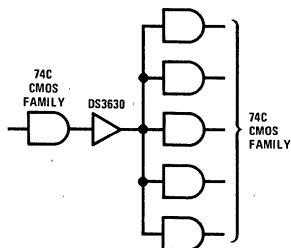


Order Number DS1630J, DS3630J
or DS3630N
See NS Package J14A or N14A

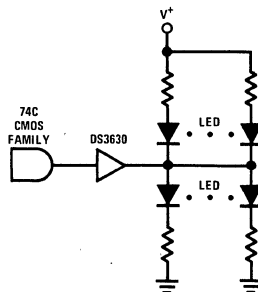
Typical Applications



CMOS To Transmission Line Interface



CMOS To CMOS Interface



LED Driver

Absolute Maximum Ratings (Note 1)

Supply Voltage	16V
Input Voltage	16V
Output Voltage	16V
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	3	15	V
Temperature (T _A)			
DS1630	-55	+125	°C
DS3630	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
I _{INH} Logical "1" Input Current	V _{IN} = V _{CC} , I _{OUT} = -400μA	DS1630		90	200	μA
		DS3630		90	200	μA
	V _{IN} = V _{CC} - 2.0V, I _{OUT} = 16 mA	DS1630		0.5	3.2	mA
		DS3630		0.5	1.5	mA
I _{INL} Logical "0" Input Current	V _{IN} = 0.4V, I _{OUT} = 16 mA	DS1630		-0.15	-1	mA
		DS3630		V _{CC} -150	-800	μA
V _{OH} Logical "1" Output Voltage	V _{IN} = V _{CC} , I _{OUT} = -400μA	DS1630	V _{CC} -1	V _{CC} -0.75		V
		DS3630	V _{CC} -0.9	V _{CC} -0.75		V
	V _{IN} = V _{CC} - 0.4V, I _{OUT} = 16 mA	DS1630	V _{CC} -2.5	V _{CC} -2.0		V
		DS3630	V _{CC} -2.5	V _{CC} -2.0		V
V _{OL} Logical "0" Output Voltage	V _{IN} = 0V, I _{OUT} = 400μA	DS1630		0.75	1	V
		DS3630		0.75	0.9	V
	V _{IN} = 0V, I _{OUT} = 16 mA	DS1630		0.95	1.3	V
		DS3630		0.95	1.3	V
	V _{IN} = 0.4V, I _{OUT} = 16 mA	DS1630		1.2	1.6	V
		DS3630		1.2	1.5	V

Switching Characteristics V_{CC} = 5.0V, T_A = 25°C unless otherwise specified

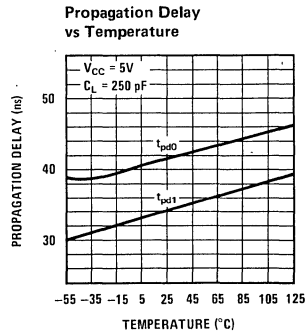
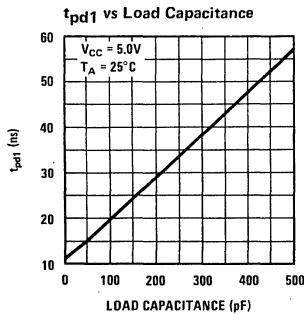
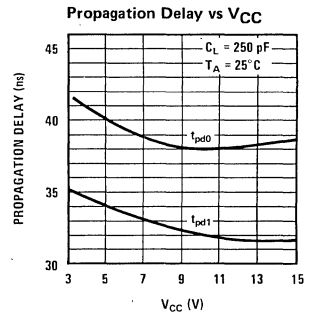
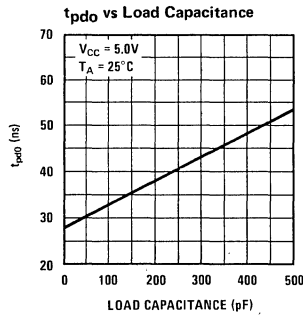
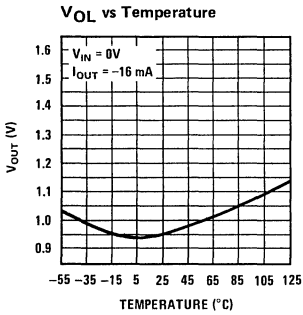
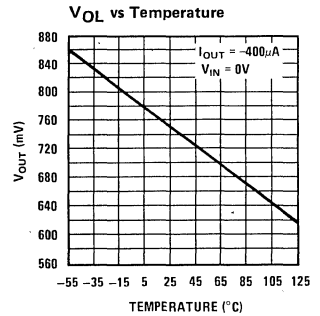
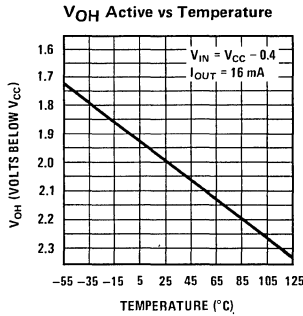
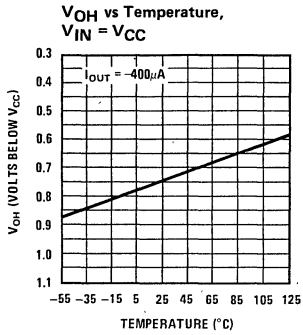
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd0} Propagation Delay to a Logical "0"	C _L = 50 pF		30	45	ns
	C _L = 250 pF		40	60	ns
	C _L = 500 pF		50	75	ns
t _{pd1} Propagation Delay to a Logical "1"	C _L = 50 pF		15	25	ns
	C _L = 250 pF		35	50	ns
	C _L = 500 pF		50	75	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

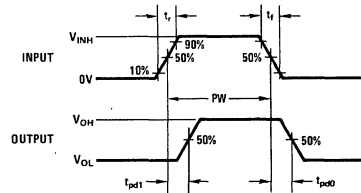
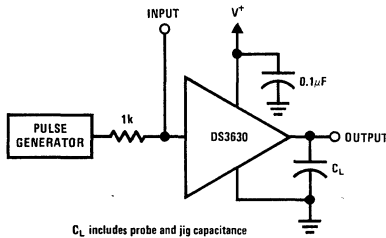
Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS1630 and across the 0°C to +70°C range for the DS3630. All typicals are given for V_{CC} = 5.0V and T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Typical Performance Characteristics



AC Test Circuit and Switching Time Waveforms



Pulse Generator characteristics: PRR = 1.0 MHz, PW = 500 ns, $t_r = t_f < 10$ ns, $V_{IN} = 0$ to V_{CC}

DS7800/DS8800 Dual Voltage Level Translator

General Description

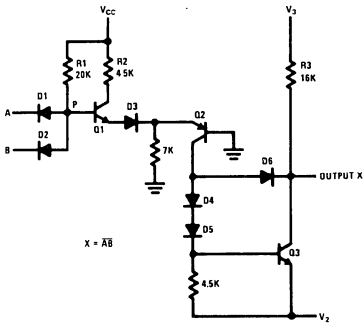
The DS7800/DS8800 are dual voltage translators designed for interfacing between conventional TTL or LS voltage levels and those levels associated with high impedance junction or MOS FET-type devices. The design allows the user a wide latitude in his selection of power supply voltages, thus providing custom control of the output swing. The translator is especially useful in analog switching; and since low power dissipation occurs in the "off" state, minimum system power is required.

Features

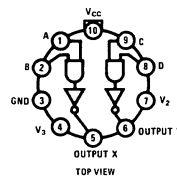
- 31 volt (max) output swing
- 1 mW power dissipation in normal state
- Standard 5V power supply
- Temperature range:

DS7800	-55°C to +125°C
DS8800	0°C to +70°C
- Compatible with all MOS devices

Schematic and Connection Diagrams



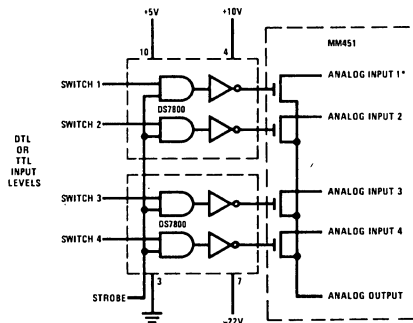
Metal Can Package



Order Number DS7800H
or DS8800H
See NS Package H10C

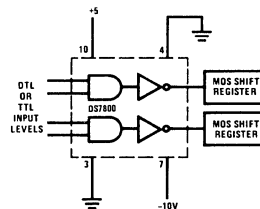
Typical Applications

4-Channel Analog Switch



*Analog signals within the range of +8V to -8V.

Bipolar to MOS Interfacing



Absolute Maximum Ratings (Note 1)

V _{CC} Supply Voltage	7.0V
V ₂ Supply Voltage	-30V
V ₃ Supply Voltage	30V
V ₃ -V ₂ Voltage Differential	40V
Input Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C
Maximum Power Dissipation* at 25°C	690 mW
Metal Can (TO-5) Package	

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7800	4.5	5.5	V
DS8800	4.75	5.25	V
Temperature (T _A)			
DS7800	-55	+125	°C
DS8800	0	+70	°C

*Derate metal can package 4.6 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP (NOTE 6)	MAX	UNITS
V _{IH}	Logical "1" Input Voltage V _{CC} = Min	2.0			V
V _{IL}	Logical "0" Input Voltage V _{CC} = Min			0.8	V
I _{IH}	Logical "1" Input Current V _{CC} = Max				
	V _{IN} = 2.4V			5	μA
	V _{IN} = 5.5V			1	mA
I _{IL}	Logical "0" Input Current V _{CC} = Max, V _{IN} = 0.4V		-0.2	-0.4	mA
I _{OL}	Output Sink Current V _{CC} = Min, V _{IN} = 2V, V ₃ Open				
	DS7800	1.6			mA
	DS8800	2.3			mA
I _{OH}	Output Leakage Current V _{CC} = Max, V _{IN} = 0.8V (Notes 4 and 7)			10	μA
R _O	Output Collector Resistor T _A = 25°C	11.5	16.0	20.0	kΩ
V _{OL}	Logical "0" Output Voltage V _{CC} = Min, V _{IN} = 2.0V (Note 7)			V ₂ + 2.0	V
I _{CC(MAX)}	Power Supply Current Output "ON" V _{CC} = Max, V _{IN} = 4.5V (Note 5)		0.85	1.6	mA
I _{CC(MIN)}	Power Supply Current Output "OFF" V _{CC} = Max, V _{IN} = 0V (Note 5)		0.22	0.41	mA

Switching Characteristics T_A = 25°C, nominal power supplies unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd0}	Transition Time to Logical "0" Output T _A = 25°C, C = 15 pF (Note 8)	25	70	125	ns
t _{pd1}	Transition Time to Logical "1" Output T _A = 25°C, C = 15 pF (Note 9)	25	62	125	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7800 and across the 0°C to +70°C range for the DS8800.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Current measured is drawn from V₃ supply.

Note 5: Current measured is drawn from V_{CC} supply.

Note 6: All typical values are measured at T_A = 25°C with V_{CC} = 5.0V, V₂ = -22V, V₃ = +8V.

Note 7: Specification applies for all allowable values of V₂ and V₃.

Note 8: Measured from 1.5V on input to 50% level on output.

Note 9: Measured from 1.5V on input to logic "0" voltage, plus 1V.

Theory of Operation

The two input diodes perform the AND function on TTL input voltage levels. When at least one input voltage is a logical "0", current from V_{CC} (nominally 5.0V) passes through R_1 and out the input(s) which is at the low voltage. Other than small leakage currents, this current drawn from V_{CC} through the 20 k Ω resistor is the only source of power dissipation in the logical "1" output state.

When both inputs are at logical "1" levels, current passes through R_1 and diverts to transistor Q_1 , turning it on and thus pulling current through R_2 . Current is then supplied to the PNP transistor, Q_2 . The voltage losses caused by current through Q_1 , D_3 , and Q_2 necessitate that node P reach a voltage sufficient to overcome these losses before current begins to flow. To achieve this voltage at node P, the inputs must be raised to a voltage level which is one diode potential lower than node P. Since these levels are exactly the same as those experienced with conventional TTL, the interfacing with these types of circuits is achieved.

Transistor Q_2 provides "constant current switching" to the output due to the common base connection of Q_2 . When at least one input is at the logical "0" level, no current is delivered to Q_2 ; so that its collector supplies essentially zero current to the output stage. But when both inputs are raised to a logical "1" level current is supplied to Q_2 .

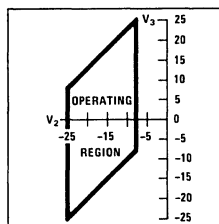
Since this current is relatively constant, the collector of Q_2 acts as a constant current source for the output stage. Logic inversion is performed since logical "1" input voltages cause current to be supplied to Q_2 and to Q_3 . And when Q_3 turns on the output voltage drops to the logical "0" level.

The reason for the PNP current source, Q_2 , is so that the output stage can be driven from a high impedance. This allows voltage V_2 to be adjusted in accordance with the application. Negative voltages to $-25V$ can be applied to V_2 . Since the output will neither source nor sink large amounts of current, the output voltage range is almost exclusively dependent upon the values selected for V_2 and V_3 .

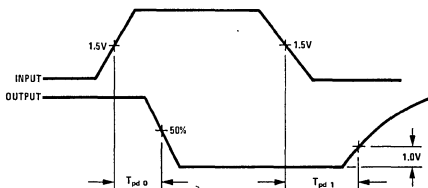
Maximum leakage current through the output transistor Q_3 is specified at 10 μA under worst-case voltage between V_2 and V_3 . This will result in a logical "1" output voltage which is 0.2V below V_3 . Likewise the clamping action of diodes D_4 , D_5 , and D_6 , prevents the logical "0" output voltage from falling lower than 2V above V_2 , thus establishing the output voltage swing at typically 2 volts less than the voltage separation between V_2 and V_3 .

Selecting Power Supply Voltage

The graph shows the boundary conditions which must be used for proper operation of the unit. The range of operation for power supply V_2 is shown on the X axis. It must be between $-25V$ and $-8V$. The allowable range for power supply V_3 is governed by supply V_2 . With a value chosen for V_2 , V_3 may be selected as any value along a vertical line passing through the V_2 value and terminated by the boundaries of the operating region. A voltage difference between power supplies of at least 5V should be maintained for adequate signal swing.



Switching Time Waveforms





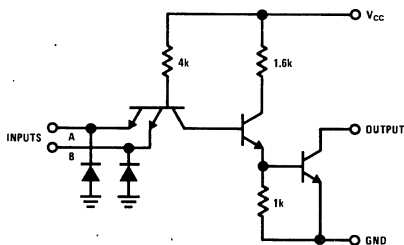
DS7810/DS8810 Quad 2-Input TTL-MOS Interface Gate
DS7811/DS8811 Quad 2-Input TTL-MOS Interface Gate
DS7812/DS8812 Hex TTL-MOS Inverter

General Description

These Series 54/74 compatible gates are high output voltage versions of the DM5401/DM7401 (SN5401/SN7401), DM5403/DM7403 (SN5403/SN7403), and DM5405/DM7405 (SN5405/SN7405). Their open-collector outputs may be "pulled-up" to +14 volts in the logical "1" state thus providing guaranteed interface between TTL and MOS logic levels.

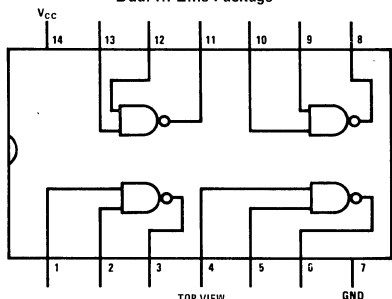
In addition the devices may be used in applications where it is desirable to drive low current relays or lamps that require up to 14 volts.

Schematic and Connection Diagrams



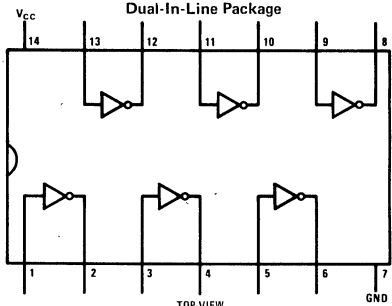
DS7810/DS8810, DS7811/DS8811

Dual-In-Line Package

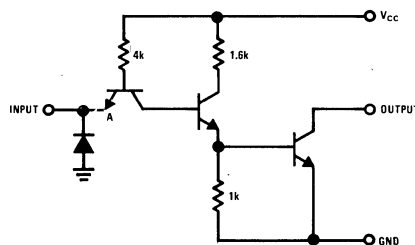


Order Number DS7810J, DS8810J,
or DS8810N
See NS Package J14A or N14A

Dual-In-Line Package

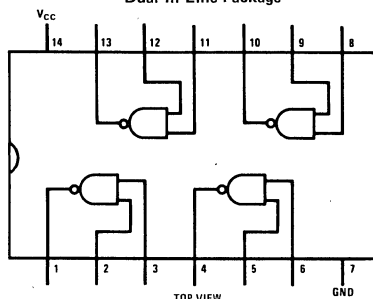


Order Number DS7812J, DS8812J,
DS7812W or DS8812N
See NS Package J14A, N14A or W14A



DS7812/DS8812

Dual-In-Line Package



Order Number DS7811J, DS8811J,
DS7811W or DS8811N
See NS Package J14A, N14A or W14A

Absolute Maximum Ratings (Note 1)

V _{CC}	7V
Input Voltage	5.5V
Output Voltage	14V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation * at 25°C	
Cavity Package	1254 mW
Molded Package	1106 mW
Lead Temperature (Soldering, 10 seconds)	300°C

* Derate cavity package 8.36 mW/°C above 25°C; derate molded package 8.85 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS78XX	4.5	5.5	V
DS88XX	4.75	5.25	V
Temperature (T _A)			
DS78XX	-55	+125	°C
DS88XX	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{CLAMP}	Input Diode Clamp Voltage	V _{CC} = 5.0V, T _A = 25°C, I _{IN} = -12 mA		-1.5	V	
V _{IH}	Logical "1" Input Voltage	V _{CC} = Min		2.0	V	
V _{IL}	Logical "0" Input Voltage	V _{CC} = Min		0.8	V	
I _{OH}	Logical "1" Output Current	V _{CC} = Min, V _{IN} = 0.8V		250	μA	
		V _{OUT} = 10V, V _{IN} = 0.0V		40	μA	
I _{OL}	Logical "0" Output Current	V _{CC} = Min, V _{IN} = 2.0V, V _{OUT} = 0.4V		16	mA	
V _{OH}	Logical "1" Output Breakdown Voltage	V _{CC} = Min, V _{IN} = 0V, I _{OUT} = 1 mA		14	V	
V _{OL}	Logical "0" Output Voltage	V _{CC} = Min, V _{IN} = 2.0V, I _{OUT} = 16 mA		0.4	V	
I _{IH}	Logical "1" Input Current	V _{CC} = Max, V _{IN} = 2.4V		40	μA	
		V _{IN} = 5.5V		1	mA	
I _{IL}	Logical "0" Input Current	V _{CC} = Max, V _{IN} = 0.4V		-1.6	mA	
I _{CC(MAX)}	Logical "0" Supply Current (Each Gate)	V _{CC} = Max, V _{IN} = 5.0V		3.0	5.1	mA
I _{CC(MIN)}	Logical "1" Supply Current (Each Gate)	V _{CC} = Max, V _{IN} = 0V		1.0	1.8	mA

Switching Characteristics T_A = 25°C, V_{CC} = 5V

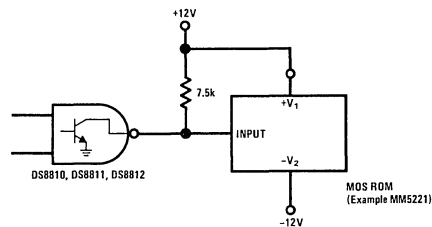
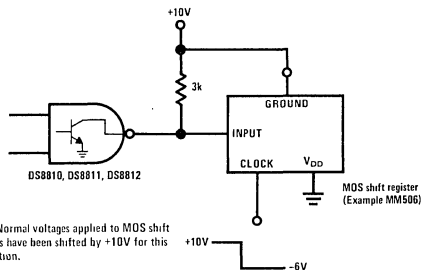
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t _{pd0}	Propagation Delay Time to a Logical "0"	C _{OUT} = 15 pF, R _L = 1k	4	12	18	ns
t _{pd1}	Propagation Delay Time to a Logical "1"		18	29	45	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

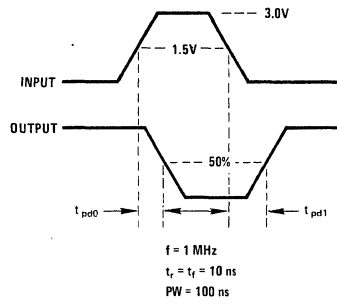
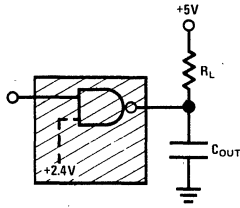
Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7810, DS7811, and DS7812 and across the 0°C to +70°C range for the DS8810, DS8811, and DS8812.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Typical Applications



AC Test Circuit and Switching Time Waveforms



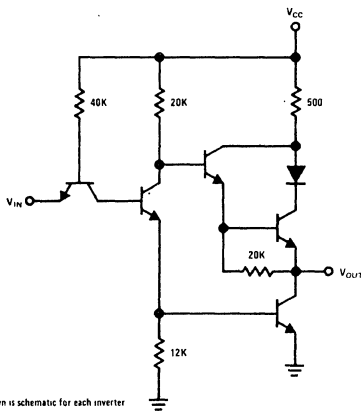
DS78L12/DS88L12 Hex TTL-MOS Inverter/Interface Gate

General Description

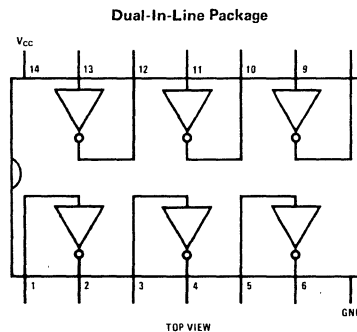
The DS78L12/DS88L12 is a low power TTL to MOS hex inverter element. The outputs may be "pulled up" to +14V in the logical "1" state, thus providing guaranteed interface between TTL and MOS logic levels. The gate may also be operated

with V_{CC} levels up to +14V without resistive pull-ups at the outputs and still providing a guaranteed logical "1" level of $V_{CC} - 2.2V$ with an output current of $-200\mu A$.

Schematic and Connection Diagrams



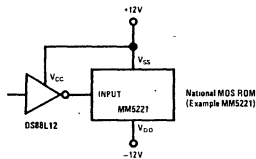
Note. Shown is schematic for each inverter



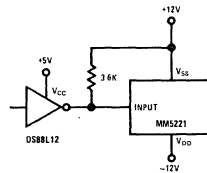
Order Number DS78L12J, DS88L12J
Order Number DS88L12N
Order Number DS78L12W
See NS Package J14A, N14A or W14A

Typical Applications

TTL Interface to MOS ROM
Without Resistive Pull-Up



TTL Interface to MOS ROM
With Resistive Pull-Up



AC Test Circuits

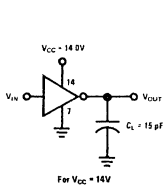


Figure 1

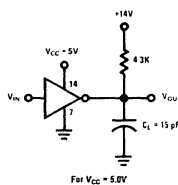
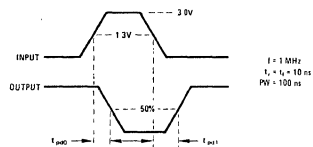


Figure 2

Switching Time Waveforms



Absolute Maximum Ratings (Note 1)

Supply Voltage	15V
Input Voltage	5.5V
Output Voltage	15V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW
Lead Temperature (Soldering, 10 sec)	300°C

*Derate cavity package 8.72 mW/°C above 25°C; derate molded package 9.66 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})			
DS78L12	4.5	5.5	V
DS88L12	4.75	5.25	V
Temperature (T_A)			
DS78L12	-55	125	°C
DS88L12	0	70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V_{IH} Logical "1" Input Voltage	$V_{CC} = 14.0V$	2.0	1.3		V	
	$V_{CC} = \text{Min}$	2.0	1.3		V	
V_{IL} Logical "0" Input Voltage	$V_{CC} = 14.0V$		1.3	0.7	V	
	$V_{CC} = \text{Min}$		1.3	0.7	V	
V_{OH} Logical "1" Output Voltage	$V_{IN} = 0.7V$	$V_{CC} = 14.0V, I_{OUT} = -200\mu A$	11.8	12.0	V	
		$V_{CC} = \text{Min}, I_{OUT} = 200\mu A$	14.5	15.0	V	
	$V_{IN} = 0V, V_{CC} = \text{Min}, I_{OUT} = -5.0\mu A$ (Note 6)				V	
V_{OL} Logical "0" Output Voltage	$V_{IN} = 2.0V$	$V_{CC} = 14.0V, I_{OUT} = 12\text{ mA}$		0.5	1.0	V
		$V_{CC} = \text{Min}, I_{OUT} = 3.6\text{ mA}$		0.2	0.4	V
I_{IH} Logical "1" Input Current	$V_{IN} = 2.4V$	$V_{CC} = 14.0V$		<1	20	μA
		$V_{CC} = \text{Max}$		<1	10	μA
	$V_{IN} = 5.5V$	$V_{CC} = 14.0V$		<1	100	μA
		$V_{CC} = \text{Max}$		<1	100	μA
I_{IL} Logical "0" Input Current	$V_{IN} = 0.4V$	$V_{CC} = 14.0V$		-320	-500	μA
		$V_{CC} = \text{Max}$		-100	-180	μA
I_{SC} Output Short Circuit Current	$V_{OUT} = 0V$ (Note 4)	$V_{CC} = 14.0V$	-10	-25	-50	mA
		$V_{CC} = \text{Max}$	-3	-8	-15	mA
I_{CCH} Supply Current – Logical "1" (Each Inverter)	$V_{IN} = 0V$	$V_{CC} = 14.0V$		0.32	0.50	mA
		$V_{CC} = \text{Max}$		0.11	0.16	mA
I_{CCL} Supply Current – Logical "0" (Each Inverter)	$V_{IN} = 5.25V$	$V_{CC} = 14.0V$		1.0	1.5	mA
		$V_{CC} = \text{Max}$		0.3	0.5	mA

Switching Characteristics $T_A = 25^\circ C$, nominal power supplies unless otherwise noted

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{pd0} Propagation Delay to a Logical "0" from Input to Output	$T_A = 25^\circ C$	$V_{CC} = 5.0V$ (Figure 2)		27	45	ns
		$V_{CC} = 14.0V$ (Figure 1)		11	20	ns
t_{pd1} Propagation Delay to a Logical "1" from Input to Output	$T_A = 25^\circ C$	$V_{CC} = 5.0V$ (Figure 2), (Note 5)		79	100	ns
		$V_{CC} = 14.0V$ (Figure 1)		34	55	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS78L12 and across the 0°C to +70°C range for the DS88L12.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: t_{pd1} for $V_{CC} = 5.0V$ is dependent upon the resistance and capacitance used.

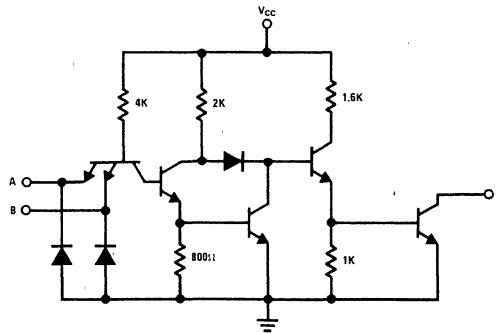
Note 6: $V_{OH} = V_{CC} - 1.1V$ for the DS88L12 and $V_{CC} - 1.4V$ for the DS78L12.

DS7819/DS8819 Quad 2-Input TTL-MOS AND Gate

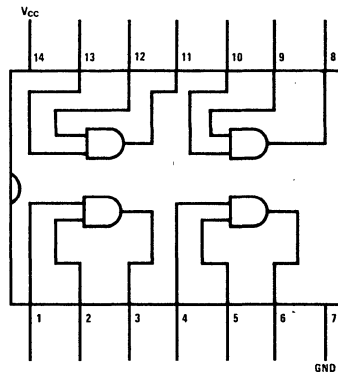
The DS7819/DS8819 is the high output voltage version of the SN5409. Its open-collector outputs may be "pulled-up" to 14V in the logical "1"

state thus providing guaranteed interface between TTL and MOS logic levels.

Schematic and Connection Diagrams

4


Dual-In-Line Package



TOP VIEW

Order Number DS7819J or DS8819J
 Order Number DS8819N
 Order Number DS7819W
 See NS Package J14A, N14A or W14A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Input Voltage	5.5V
Output Voltage	15V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1254 mW
Molded Package	1106 mW
Lead Temperature (Soldering, 10 sec)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7819	4.5	5.5	V
DS8819	4.75	5.25	V
Temperature (T _A)			
DS7819	-55	+125	°C
DS8819	0	70	°C

* Derate cavity package 8.36 mW/°C above 25°C; derate molded package 8.85 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{IH}	Logical "1" Input Voltage	V _{CC} = Min	2.0		V
V _{IL}	Logical "0" Input Voltage	V _{CC} = Min		0.8	V
I _{OH}	Logical "1" Output Current	V _{CC} = Min		40.0	μA
		V _{IN} = 2.0V, V _{OUT} = 10V		1.0	mA
		V _{IN} = 4.5V, V _{OUT} = 14V			
V _{OL}	Logical "0" Output Voltage	V _{CC} = Min, V _{IN} = 0.8V, I _{OUT} = 16 mA		0.4	V
I _{IH}	Logical "1" Input Current	V _{CC} = Max		40.0	μA
		V _{IN} = 2.4V		1.0	mA
		V _{IN} = 5.5V			
I _{IL}	Logical "0" Input Current	V _{CC} = Max, V _{IN} = 0.4V		-1.6	mA
I _{CC1}	Logical "1" Supply Current	V _{CC} = Max, V _{IN} = 5V		11.0	mA
I _{CC2}	Logical "0" Supply Current	V _{CC} = Max, V _{IN} = 0V		20.0	mA
V _{CL}	Input Clamp Voltage	V _{CC} = 5.0V, T _A = 25°C, I _{IN} = -12 mA		-1.5	V

Switching Characteristics T_A = 25°C, V_{CC} = 5V

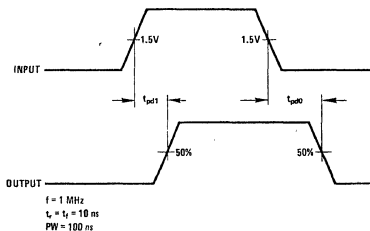
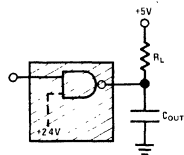
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t _{pd0}	Propagation Delay to a Logical "0"	C _{OUT} = 15 pF, R _L = 400Ω		16.0	24.0	ns
t _{pd1}	Propagation Delay to a Logical "1"			16.0	32.0	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7819 and across the 0°C to +70°C range for the DS8819.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

AC Test Circuit and Switching Time Waveforms





Section 5 Display Controllers/ Drivers

5

TEMPERATURE RANGE		DESCRIPTION	PAGE NUMBER
-55°C to +125°C	0°C to +70°C		
—	DP8350	Series CRT Controllers	5-6
—	AN-199	A Low Component Count Video Data Terminal Using the DP8350 CRT Controller and the INS8080 CPU	5-30
—	AN-212	Graphics Using the DP8350 Series of CRT Controllers	5-44
—	AN-243	Graphics/Alphanumerics Systems Using the DP8350	5-48
—	AN-270	Software Design for a High Speed (38.4 kbaud) Data Terminal	5-76
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—	DS8874	9-Digit Shift Input LED Driver	5-145
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DP8350 CRT CONTROLLER SERIES SELECTION GUIDE

Item No.	Parameter	DP8350 Value		DP8352 Value		DP8353 Value		
1	Character Font Size (Reference Only)	Dots per Character (Width)		(7)		(7)		
2		Scan Lines per Character (Height)		(9)		(9)		
3	Character Field Cell Size	Dots per Character (Width)		9		9		
4		Scan Lines per Character (Height)		12		12		
5	Number of Video Characters per Row		80		32		80	
6	Number of Video Character Rows per Frame		24		16		25	
7	Number of Video Scan Lines (Item 4 x Item 6)		240		192		300	
8	Frame Refresh Rate (Hz)		f1 = 60	f0 = 50	f1 = 60	f0 = 50	f1 = 60	f0 = 50
9	Delay after Vertical Blank Start to Start of Vertical Sync (Number of Scan Lines)		4	30	27	53	0	32
10	Vertical Sync Width (Number of Scan Lines)		10	10	3	3	3	3
11	Interval between Vertical Blank Start and Start of Video (Number of Scan Lines of Video Blanking)		20	72	68	120	20	84
12	Total Scan Lines per Frame (Item 7 + Item 11)		260	312	260	312	320	384
13	Horizontal Scan Frequency (Line Rate) (Item 8 x Item 12)		15.6 kHz		15.6 kHz		19.20 kHz	
14	Number of Character Times per Scan Line		100		50		102	
15	Character Clock Rate (Item 13 x Item 14)		1.56 MHz		0.78 MHz		1.9584 MHz	
16	Character Time (1 ÷ Item 15)		641 ns		1282 ns		510.6 ns	
17	Delay after Horizontal Blank Start to Horizontal Sync Start (Character Times)		0		6		5	
18	Horizontal Sync Width (Character Times)		43		4		9	
19	Dot Frequency (Item 3 x Item 15)		10.92 MHz		7.02 MHz		17.6256 MHz	
20	Dot Time (1 ÷ Item 19)		91.6 ns		142.4 ns		56.7 ns	
21	Vertical Blanking Output Stop before Start of Video (Number of Scan Lines)		1		0		1	
22	Cursor Enable on All Scan Lines of a Row? (Yes or No)		Yes		Yes		Yes	
23	Does the Horizontal Sync Pulse Have Serrations during Vertical Sync? (Yes or No)		No		Yes		No	
24	Width of Line Buffer Clock Logic "0" State within a Character Time (Number of Dot Time Increments)		4		5		5	
25	Serration Pulse Width, if Used (Character Times)		—		4		—	
26	Horizontal Sync Pulse Active State Logic Level (1 or 0)		1		0		1	
27	Vertical Sync Pulse Active State Logic Level (1 or 0)		0		0		1	
28	Vertical Blanking Pulse Active State Logic Level (1 or 0)		1		1		1	

Video Monitor Format: Ball Brothers TV-12, TV-120 or Equivalent. (DP8350)

Video Monitor Format: RS-170-Compatible (Standard American TV). (DP8352)

Video Monitor Format: Motorola M3003 or Equivalent. (DP8353)

LED DISPLAY SEGMENT DRIVERS

Drivers/ Package	I _O /Segment (mA)		V _{MAX} (V)		Comments	Device Number		Page No.
	Sink* (Common Anode)	Source (Common Cathode)	Input	Supply		0°C to +70°C	-55°C to +125°C	
4		30	10	10	Programmable constant current	DS75493	DS55493	5-109
4	50	50	15	10		DS75491		5-106
5	50	50	15	10	Programmable output, active high latch Programmable output, active low latch Constant current output	DS8861		5-136
6	32		5.5	7		DS8859A		5-133
6	32		5.7	7		DS8869A		5-133
8		18	10	7		DS8867		5-139
8		50	36	36		DS8654		5-113
14	25		6.6	7		BCD input, dual-display driver		DS8669

*Digit drivers with output sink capability may be used to drive segments of "common anode" displays

LED DISPLAY DIGIT DRIVERS

Drivers/ Package	I _O /Digit (mA)		V _{MAX} (V)		Comments	Device Number		Page No.
	Sink (Common Cathode)	Source (Common Anode)	Input	Supply		0°C to +70°C	-55°C to +125°C	
4		50	10	10	DS75492 pinout, 4.5V to 9V systems Enable control	DS75491	DS55494	5-106
6	50		10	10		DS8877		5-147
6	150		10	10	DS75492 pinout, Darlington output Open-collector saturating outputs	DS75494		5-111
6	250		10	10		DS75492		5-106
6	350		10	10		DS8870		5-141
8	40		11	11		DS8871		5-143
8	350		25	25		DS8692		5-126
8	500		15	10		DS8863		5-136
	500		23	18		DS8963		5-136
		50	36	36		DS8654		5-113
9	40		11	11		DS8872		5-143
	40		11	11		Low battery indicator		DS8873
	50		10	10	Serial shift register input	DS8874	5-145	
	100		10	10	3-cell operation—low battery indicator	DS8973	5-166	
	100		10	10	No low battery indicator	DS8975	5-166	
10	400		9.5	45	Serial input	DS3654	3-29	
14	80		10	10	On-board osc., 4 line code input, low battery indicator	DS8664	5-117	
	80	13	10	10	6 sink, 8 source outputs	DS8666	5-120	

GAS DISCHARGE DISPLAY DRIVERS

Device Type	Drivers/Package	Comments	Device Number		Page No.
			0°C to +70°C	-55°C to +125°C	
Cathode drivers	7	BCD to 7-segment	DS8880	DS7880	5-149
	7	BCD to 7-segment with comma and DP	DS8884A		5-156
	7	MOS to high voltage cathode buffer	DS8885		5-158
	8	Active high inputs	DS8889	DS7889	5-160
Anode drivers	6	Active low inputs	DS8891A		5-164
	8	Active high inputs	DS8887		5-160
	8	Active low inputs	DS8897A	DS7897A	5-160

VACUUM FLUORESCENT DISPLAY DRIVERS

Device Type	Drivers/Package	Comments	Device Number		Page No.
			0°C to +70°C	-55°C to +125°C	
Ground driver (segments)	8	7-segment plus DP	DS8654		5-113
Anode driver (digit)	8		DS8654		5-113
	16	4 line BCD input	DS8881		5-152

PRINTER DRIVERS

Device Type	Drivers/Package	Description	Device Number		Page No.
			0°C to +70°C	-55°C to +125°C	
Mechanical printer		Relay driver	DS3680		3-44
		10 hammer serial input driver	DS3654		3-29
		Seiko model 310 print head, interface set	DS8692,		5-126
			DS8693,		5-126
			DS8694		5-126
Thermal printer		8-digit driver	DS8654		5-113
		Diode matrix	DS8656		5-113

DP8350 Series CRT Controllers

General Description

The DP8350 Series of CRT Controllers are single-chip bipolar (I²L technology) circuits in a 40-pin package. They are designed to be dedicated CRT display refresh circuits. Three standard products are available, designated DP8350, DP8352, DP8353. Custom devices, however, are available in a broad range of mask programmable options.

The CRT Controller (CRTC) provides an internal dot rate crystal controlled oscillator for ease of system design. For systems where a dot rate clock is already provided, an external clock may be inputted to the CRTC. In either case system synchronization is made possible with the use of the buffered Dot Rate Clock Output.

The DP8350 Series has 11 character generation related timing outputs. These outputs are compatible for systems with or without line buffers, using character ROMs, or DM86S64-type latch/ROM/shift register circuits.

12 bits (4k) of bidirectional TRI-STATE[®] character memory addresses are provided by the CRTC for direct interface to character memory.

Three on-chip registers provide for external loading of the row starting address, cursor address, and top-of-page address.

A complete set of video outputs is available including cursor enable, vertical blanking, horizontal sync, and vertical sync.

The DP8350 Series CRTC provides for a wide range of programmability using internal mask programmable ROMs:

TRI-STATE is a registered trademark of National Semiconductor Corp.

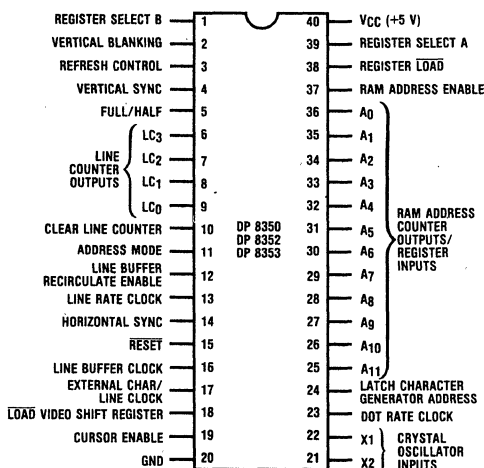
- Character Field (both number of dots/character and number of scan lines/character)
- Characters per Row
- Character Rows per Video Frame
- Format of Video Outputs

The CRTC also provides system sync and program inputs including Refresh Control, Reset, and Address Mode.

Features

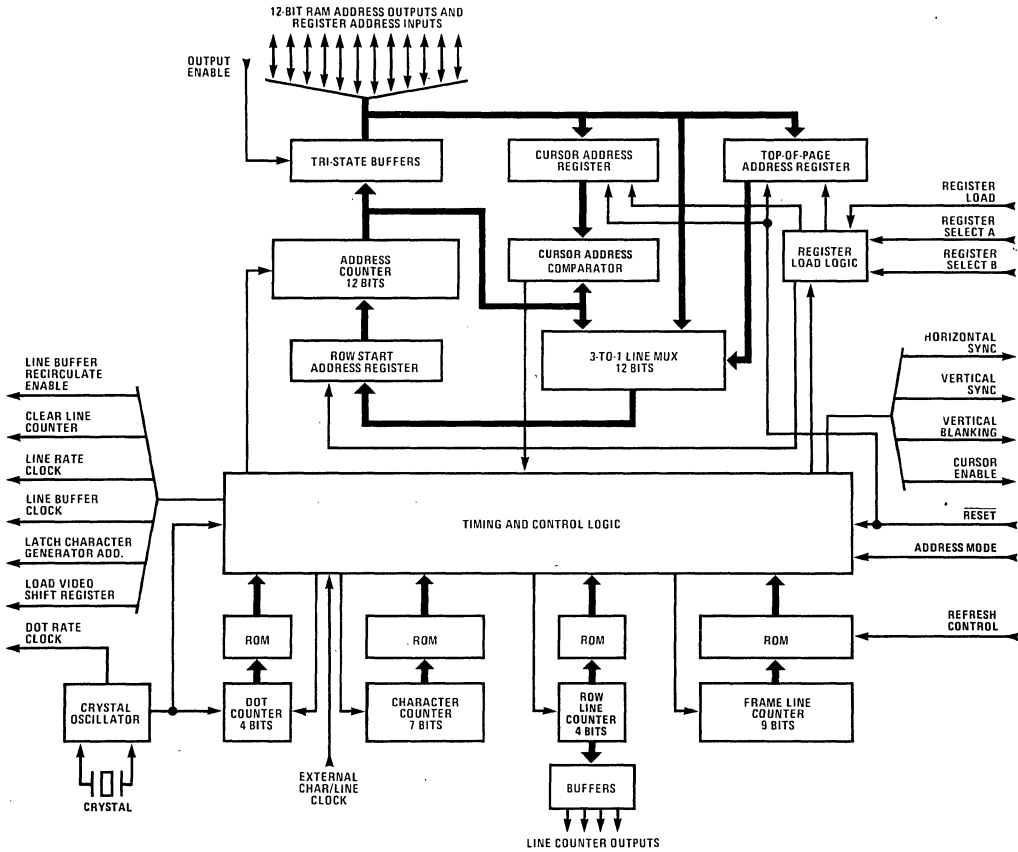
- Internal crystal controlled dot rate oscillator
- External dot rate clock input
- Buffered dot rate clock output
- Timing pulses for character generation
- Character memory address outputs (12 bits)
- Internal cursor address register
- Internal row starting address register
- Internal top-of-page address register (for scrolling)
- Programmable horizontal and vertical sync outputs
- Programmable cursor enable output
- Programmable vertical blanking output
- 2 programmable refresh rates, pin selectable
- Programmable characters/row (128 max.)
- Programmable character field size (up to 16 dots x 16 scan line field size)
- Programmable scan lines/frame (512 max.)
- Programmable character rows/frame
- Single +5V power supply
- Inputs and outputs TTL compatible
- Direct interface with DM86S64 character generator
- Ease of system design/application

Connection Diagram



Order Number DP8350N, DP8352N or DP8353N
See NS Package N40A

Block Diagram



The Video Display

Discussion of the CRT Controller necessitates an understanding of the video display as presented by a raster scan monitor. The resolution of the data displayed on the monitor screen is a function of the dot size. As shown in Figure 1, the dot size is determined by the frequency of the system dot clock. The visible size of the dot can be modified to less than 100% by external gating of the serial video data. The CRT Controller organizes the dots

into cell groupings that define video rows. These cells are accessed by a specific horizontal address output (4096 maximum) and are resolved by a row scan-line-counter output (16 maximum) as shown in Figure 2. The relation of the video portion of a frame to the horizontal blanking and vertical blanking intervals is shown in Figure 3 in a two-dimensional format.

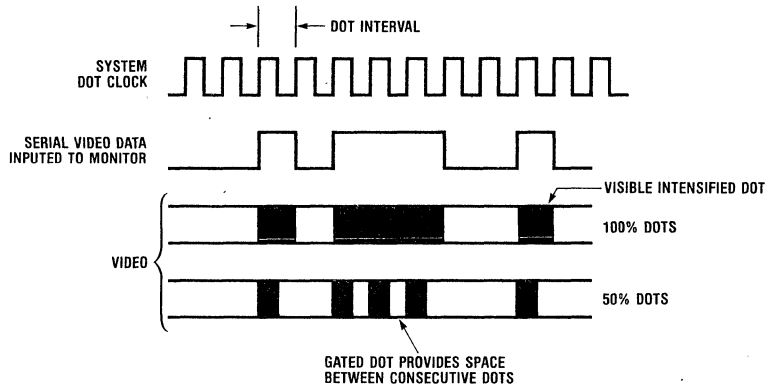


Figure 1. Dot Definition

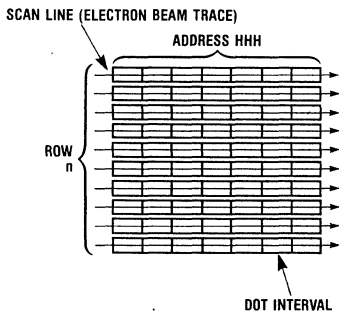


Figure 2. Character Cell Definition
(Example Shown is a 7 x 10 Character Cell)

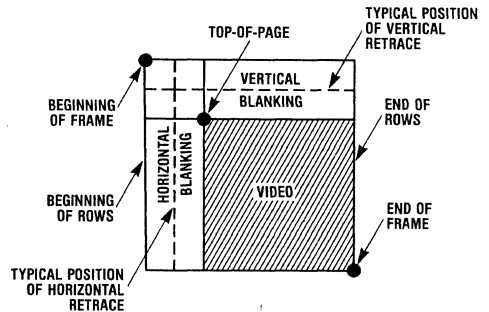


Figure 3. Frame Format Definition

Character Generation/Timing Outputs

The CRT controller provides 11 interface timing outputs for line buffers, character generator ROMs, DM86S64-type latch/ROM/shift register combination character generators, and system status timing. All outputs are buffered to provide TTL compatible direct interface to popular system circuits such as:

- DM86S64 Series Character Generators
- MM52116 Series Character ROMs
- DM74166 Dot Shift Register
- MM5034, MM5035 Octal 80-Bit Shift Registers (Line Buffers)

Dot Rate Clock: This output is provided for use in system synchronization and interface to the dot shift register used in character generation. This output is non-inverting with respect to an external clock applied to the X1 oscillator input (see Figure 6). The dot rate clock output exhibits a 50% duty cycle. All CRT controller logic transitions are synchronous with the rising edge of the Dot Rate Clock output.

Latch Character Generator Address (Character Rate Clock): This output provides an active clock pulse at character rate frequency which is active at all times. The rising edge of this pulse is synchronous with the beginning of each character cell. This output is intended for direct interface to character/video generation data latch registers.

Line Rate Clock: This output provides an active clock pulse at scan-line rate frequency (horizontal frequency), which is active at all times. The falling edge of this pulse is synchronous with the beginning of horizontal blanking. This output is intended for direct interface to character generation scan line counters.

Load Video Shift Register: This output provides a character rate signal intended for direct interface to the video dot shift register used in character generation. Active low pulses are outputted only during video time. As a result of the inactive time, horizontal and vertical video blanking can be derived from this output signal.

Clear Line Counter: This output signal is active only during the first scan line of all rows. It exhibits an active low pulse identical and synchronous to the Line Rate Clock and is provided for direct interface to character generation scan line counters.

Line Counter Outputs (LC₀ to LC₃): These outputs clock at line rate frequency, synchronous with the falling edge of the line rate clock, and provide a consecutive binary count for each scan line within a row. These outputs are provided for system designs that require decoded information indicating the present scan line position within a row. These outputs are always active, however, the next to the last row during vertical blanking will exhibit an invalid line count as a function of internal frame synchronization.

Line Buffer Clock: This output directly interfaces to data shift registers when they are incorporated as line buffers in a system design (see Figure 16). This signal is active at character rate frequency and is intended for shift registers that shift on a falling edge clock. This output is inactive during all horizontal blanking intervals yielding the number of active clocks per scan line equal to the number

of video characters per row. For custom requirements, the duty cycle of this output is mask programmable.

Line Buffer Recirculate Enable: This output is provided to control the input loading mode of the data shift register (line buffer) when used in a system design. The format of this output is intended for shift registers that load external data into the input with the mode control in the low state, and load output data into the input (recirculate) with the mode control in the high state. This output will transition to the low state, synchronous with the line rate clock falling edge, for one complete scan line of each row. The position of this scan line will either be the first scan line of the addressed row, or the last scan line of the previous row depending upon the logic level of the address mode input (pin 11), tabulated in Table 3.

Memory Address Outputs/Inputs and Registers

Address Outputs (A₀-A₁₁): These 12 address bits (4k) are bi-directional TRI-STATE® outputs that directly interface to the system RAM memory address bus.

In the output mode (enabled), these outputs will exhibit a specific 12-bit address for each video character cell to be displayed on the CRT screen. This 12-bit address increments sequentially at character rate frequency and is valid at the address bus 2 character times prior to the addressed character appearing as video on the CRT screen. This pipelining by 2 characters is provided to allow sufficient time for first, accessing the RAM memory, and second, accessing the character generation memory with the RAM memory data. Since a character cell is comprised of several scan lines of the CRT beam, the sequential address output string for a given video row is identically repeated for each scan line within the row. The starting address for each video scan line is stored within an internal 12-bit register called the Row Start Register. At the beginning of each video scan line, the internal address counter logic is preset with the contents of the Row Start Register (see Figure 4). To accomplish row by row sequential addressing, internal logic updates the Row Start Register at the beginning of the first scan line of a video row with the last address + 1 of the last scan line of the previous video row. Since the number of address locations on the video screen display is typically much less than the 4k dimension of the 12-bit address bus, an internal 12-bit register called the Top Of Page Register, contains the starting address of the first video row. Internal logic loads the contents of this top of page register into the Row Start Register at the beginning of the first scan line of the first video row. The Top Of Page Register is loaded with address zero whenever the Reset input is pulsed to the logic "0" state.

In the input mode (disabled), external addresses can be loaded into the internal 12-bit registers by external control of the register select A, register select B, and register load inputs (see Table 1). As a result of specific external loading of the contents of the Row Start Register, Top Of Page Register, and the Cursor Register, row by row page scrolling, non-sequential row control, and cursor location control, can easily be accomplished.

During the non-video intervals, the address output operation is modified. During all horizontal blanking intervals, the incrementing of the address counter is inhibited and the address count is held constant at the last video address + 1. For example, if a video row has an 80 character cell format and addressing for the video portion of a given scan line starts at address 1, the address counter will increment up through address 81. Address 81 is held constant during the horizontal blanking interval until 3 character times before the next video scan line. At this point, the address counter is internally loaded with the contents of the Row Start Register which may contain address 1 or 81 as a function of internal control, or a new address that was loaded from the external bus. During vertical blanking, however, this loading of the internal address counter with the contents of the Row Start Register is inhibited providing scan line by scan line sequential address incrementing. This allows minimum access time to the CRT when the address counter outputs are being used for dynamic RAM refresh.

RAM Address Enable Input: At all times the status of the bi-directional address outputs is controlled externally by the logic level of the enable input. A 'low' logic level at this input places the address outputs in the TRI-STATE® (disabled) input mode. A 'high' logic level at this input places the address outputs in the active (enabled) output mode.

Register Load/Select Inputs: When the Register Load input is pulsed to the logic 'low' state, the Top Of Page, Row Start, or Cursor Register will be loaded with a 12-bit address which originates from either the internal address counter or the external address bus (refer to discussion on register loading constraints). The destination register is selected prior to the load pulse by setting the register select inputs to the appropriate state as defined in Table 1.

Table 1. Register Load Truth Table

Register Select A (Pin 39)	Register Select B (Pin 1)	Register Load Input (Pin 38)	Register Loading Destination
0	0	0	No Select
0	1	0	Top-of-Page
1	0	0	Row-Start*
1	1	0	Cursor
X	X	1	No Load

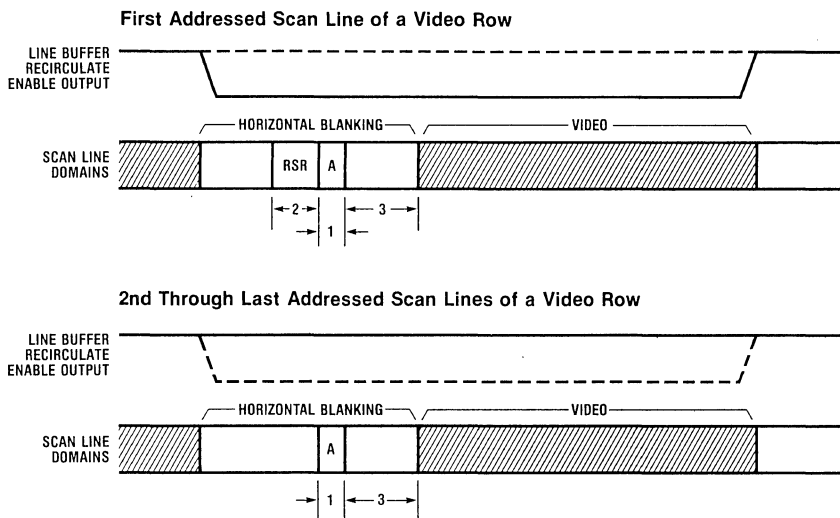
*During the vertical blanking interval, a load to this register is internally routed to the Top-Of-Page register.

Internal Registers and Loading Constraints: There are 3 internal 12-bit registers that facilitate video screen management with respect to row-by-row page scrolling, non-sequential row control and cursor location. These registers can be loaded with addresses from the external address bus while the address outputs are disabled (RAM address enable input in the low state), by controlling the register select and load inputs within the constraints of each register.

The Row-Start Register (RSR) holds the starting address for each scan line of the video portion of a frame. The video addressing format is completely determined by the contents of this register. With no external loading, the RSR is automatically loaded by internal control such that row-by-row sequential addressing is achieved. Referring to Figure 4, the RSR is loaded automatically once for each video row during the first addressed scan line. The source of the loaded address is internally controlled such that the RSR load for the first video row comes from the Top-Of-Page Register. The RSR load for all subsequent video rows comes from the address counter which holds the last displayed address + 1. If non-sequential row formatting is desired, the RSR can be loaded externally with a 12-bit address. However, this external load must be made prior to the internal automatic load. Generally speaking, the external load to the RSR should be made during the video domain of the last addressed scan line of the previous row. Figure 4 indicates the internal automatic loading intervals which must be avoided, if the load must be made during the horizontal blanking interval. Once an external address has been loaded to the RSR, the next occurring internal automatic RSR load will be inhibited by internal detection logic. If an external load is made to the RSR during the vertical blanking interval, the 12-bit address is loaded into the Top-Of-Page Register instead of the RSR as a result of internal control. This internal function is performed due to the fact that the address loaded into the RSR for the first video row can only come from the Top-Of-Page Register.

The Top-Of-Page register (TOPR) holds the address of the first character of the first video row. As a function of internal control the contents of this register are loaded into the RSR at the beginning of the first addressed scan line of the first video row (see Figure 4). This loading operation is strictly a function of internal control and cannot be overridden by an external load to the RSR. For this reason, any external load to the RSR during the vertical blanking interval is interpreted internally as a TOPR load. When the Reset input is pulsed to the logic "0" state, the TOPR register is loaded with address zero by internal control. This yields a video page display with the first row of sequential addressing beginning at zero. Page scrolling can be accomplished by externally loading a new address into the TOPR. This loading operation can be performed at any time during the frame prior to the interval where the TOPR is loaded automatically into the RSR (see Figure 4). Once the TOPR has been loaded, it does not have to be accessed again until the contents are to be modified.

The Cursor Register (CR) holds the present address of the cursor location. A true comparison of the address counter outputs and the contents of the CR results in a Cursor Enable output signal delayed by two character times. When the Reset input is pulsed to the logic "0" state, the contents of the CR are set to address zero by internal control. Modifying the contents of the CR is accomplished by external loading at any time during this frame. Typically, loading is performed only during intervals when the address outputs are not actively controlling the video display. Once the CR has been loaded, it does not have to be accessed again until the contents are to be modified.



Note 1: Dimensions are in character time intervals.

Note 2: "A" denotes the interval that the address counter is preset with the contents of the Row Start Register.

Note 3: "RSR" denotes the interval that the Row Start Register is internally loaded with either the contents of the Top-Of-Page Register (1st video row) or the last video address + 1 from the address counter.

Figure 4. Automatic Internal Loading Intervals

Video-Related Outputs

Horizontal Sync: This output provides the necessary scan line rate sync signal for direct interface to either three-terminal or composite sync monitors. The pulse width, position, and logic polarity are mask programmable, in character time increments, for custom requirements. This output may also be mask programmed to have RS-170 compatible serration pulses during the vertical sync interval (refer to DP8352 format and Figure 15).

Vertical Sync: This output provides the necessary frame rate sync signal for direct interface to either three-terminal or composite sync monitors. The pulse width, position, and logic polarity are mask programmable, in scan line increments, for custom requirements.

Cursor Enable: This output provides a signal that is intended to be combined with the video signal to display a cursor attribute which serves as a visual pointer for video RAM location. Internally, the 12-bit address count is continuously being compared with the 12-bit address stored in the Cursor Register. When a true compare is detected, an active high level signal will be present at the Cursor Enable output, delayed by 2 character times after the corresponding address bus output. The signal

is delayed by 2 character times so that it will be coincident with the video information resulting from the corresponding address. Mask programmability allows the cursor enable output signal to be formatted such that a signal will be outputted for all addressed scan lines of a video character cell or any single scan line of that cell. The cursor enable output signal is inhibited during the horizontal and vertical blanking intervals so that video blanking is maintained. When the addressing is advanced by setting the address mode input (pin 11) in the logic "0" state, the cursor enable signal will also be shifted with respect to the scan line count. Specifically, for a character cell with the cursor output active on all addressed scan lines of the cell, the first scan line of the cursor signal will occur at the last scan line count of the previous video row, and the last scan line count of the addressed character cell will have no cursor output signal. This mode of operation gives rise to a unique situation for the first video row where the first addressed scan line of a character cell has no cursor output signal since its advanced scan line position is inhibited by the vertical blanking interval.

CRT System Control Functions

Refresh Control Input: This input provides a logic level selectable CRT system refresh rate. Typically, this input will select either a 60 Hz or 50 Hz refresh rate to provide geographical marketing flexibility. However, mask programmability provides the capability of a wide range of frequencies for custom requirements. For definition of the input logic truth table and the refresh rate format, refer to Table 2 and the standard device type format tables.

Table 2. Refresh Rate Select Truth Table

Refresh Control (Pin 3) Logic Level	Frame Refresh Rate			
	Symbol	DP8350	DP8352	DP8353
1	f1	60 Hz	60 Hz	60 Hz
0	f0	50 Hz	50 Hz	50 Hz

Vertical Blanking Output: This output provides a signal that transitions at the end of the last video scan line of the last video row and indicates the beginning of the vertical blanking interval. This signal transitions back to the inactive state during the row of scan lines just prior to the first video row. The transition position within this last row of vertical blanking, as well as the active logic polarity, is a function of the particular device format (item 21 of the format tables) or is mask programmable for custom requirements.

Address Mode: When a system utilizes a line buffer shift register, the first scan line of addressing for a row is used to load the shift register. As a result of this loading operation, addressing for a particular row will not begin accessing the video RAM until the second scan line of addressing for the row. It also follows that the first scan line of a row can only exhibit addressed data for the previous video row that is in the shift register. This offset in addressing becomes a problem for character generation designs that output video on the first scan line of a row (with respect to the line counter outputs). The result is invalid data being displayed for the first scan line. One solution would be to utilize a character generation design that began outputting video on the second scan line of a row. However, since most single chip character generators begin video on the first scan line, the DP8350 series CRT controller provides a pin selectable advanced addressing mode which will compensate for addressing shifts resulting from shift register loading. Referring to Table 3, a high logic level at this input will cause addressing to be coincident with the scan line counter positions of a row, and a low logic level at this input will cause addressing to start on the last scan line counter position of the previous row. This shifted alignment of the addressing, with respect to the designated scan lines of a row, is diagrammed in Figure 5. Characteristically, it follows that, when addressing is advanced by one scan line, the Line Buffer Recirculate Enable output and the Cursor Enable output are also advanced by one scan line. This advanced position of the Cursor Enable output may deserve special consideration depending upon the system design.

Table 3. Address Mode Truth Table

Address Mode Input (Pin 11) (Logic Level)	New Row Addressing At Address Outputs and Line Buffer Recirculate Enable Logic Low Level (Scan Line Position)
0	Last scan line of previous row
1	First scan line of row.

Full/Half Row Control: This control input is provided for applications that require the option of half-page addressing. As an example, if the normal video page format is 80 characters/row by 24 rows, setting this input to the logic "0" state will cause the video format to become evenly spaced at 80 characters/row by 12 rows. Specifically, when this input is in the logic "0" state, row addressing is repeated for every other row. This yields successive groups of two rows of identical addressing. The second row of addressing, however, has the Load Video Shift Register output and the Cursor Enable output internally inhibited to provide the necessary video blanking. Setting this input to the logic "1" state yields normal frame addressing.

External Character/Line Rate Clock: This input is intended to aid testing of the CRT and is not meant to be used as an active input in a CRT system. When this input is left open, it is guaranteed not to interfere with normal operation.

Reset Input: This input is provided for power-up synchronization. When brought to the logic "0" state, device operation is halted. Internal logic is set at the beginning of vertical blanking, and the Top-Of-Page Register and the Cursor Register are loaded with address zero. When this input returns to the logic "1" state, device operation resumes at the vertical blanking interval followed by video addressing which begins at zero. This input has hysteresis and may be connected through a resistor to V_{CC} and through a capacitor to ground to accomplish a power-up Reset. The logic "0" state should be maintained for a minimum of 250 ns.

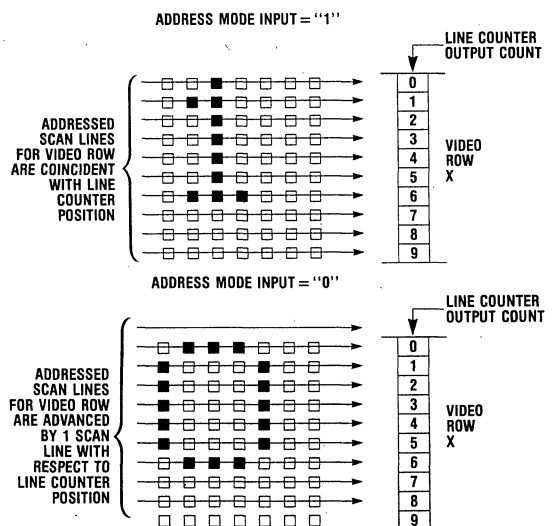


Figure 5. Address Mode Functionality

Crystal Inputs X1 and X2: The "Pierce"-type oscillator is controlled by an external crystal providing parallel resonant operation. Connection of external bias components is made to pin 22 (X1) and pin 21 (X2) as shown in Figure 6. It is important that the crystal be mounted in close proximity to the X1 and X2 pins to ensure that printed circuit trace lengths are kept to an absolute minimum. Typical specifications for the crystal are shown in Table 4 for each of the standard products, DP8350, DP8352, and DP8353. When customer mask options require higher frequencies, it may be necessary to change the crystal specifications and biasing components. If the CRTC is to be clocked by an external system dot clock, pin 22 (X1) should be driven directly by Schottky family logic while pin 21 (X2) is left open. The typical threshold for pin 22 (X1) is $V_{CC}/2$.

Table 4. Typical Crystal Specifications

Parameter	Specification		
	DP8350	DP8352	DP8353
Type	At-Cut		
Frequency	10.92 MHz	7.02 MHz	17.6256 MHz
Tolerance	0.005% at 25°C		
Stability	0.01% from 0°C to +70°C		
Resonance	Fundamental, Parallel		
Maximum Series Resistance	50Ω		
Load Capacitance	20 pF		

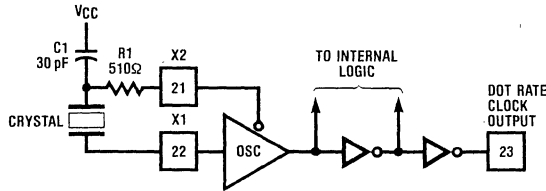


Figure 6. Dot Clock Oscillator Configuration with Typical External Bias Circuitry Shown

Custom Order Mask Programmability: The DP8350 Series CRT controller is available in three standard options designated DP8350, DP8352, and DP8353. The functional format of these devices was selected to meet the typical needs of CRT terminal designs. In order to accommodate specific customer formats, the DP8350 series CRT controller is mask programmable with a diverse range of options available. The items listed in the program table worksheet indicate the available options, while Table 5 tabulates the programming constraints.

Table 5. Mask Programming Limitations

Designation	Parameter	Min. Value	Max. Value
f_{DOT}	Dot Rate Frequency	DC	30 MHz
f_{CHAR}	Character Rate Frequency	DC	2.5 MHz
—	Line Buffer Clock Logic "0" Width (Item 20 x Item 24)	200 ns	
Item 3	Dots per Character Field Width	4	16
Item 4	Scan Lines per Character Field	2	16
Item 12	Scan Lines per Frame	512	
Item 14	Character Times per Row	Video	5 122
		Blanking	6 123
Item 11	Scan Lines per Vertical Blanking	(Item 4) + 2	

If the cursor enable output, Item 22, is active on only one line of a character row, then Item 21 value must be either "1" or "0" or equivalent to the line selected for the cursor enable output.

DP8350 Series Custom Order Format Table

This table is provided as a worksheet to aid in determining the programmed configuration for custom mask options. Refer to Table 5 for a list of programming limitations.

Item No.	Parameter	Value	
1	Character Font Size (Reference Only)	Dots per Character (Width)	
2		Scan Lines per Character (Height)	
3	Character Field Block Size	Dots per Character (Width)	
4		Scan Line per Character (Height)	
5	Number of Video Characters per Row		
6	Number of Video Character Rows per Frame		
7	Number of Video Scan Lines (Item 4 × Item 6)		
8	Frame Refresh Rate (Hz) (two pin selectable frequencies allowed) (Item 13 ÷ Item 12)	f1=	f0=
9	Delay after Vertical Blank start to start of Vertical Sync (Number of Scan Lines)		
10	Vertical Sync Width (Number of Scan Lines)		
11	Interval between Vertical Blank start and start of Video (Number of Scan Lines of Video Blanking)		
12	Total Scan Lines per Frame (Item 7 + Item 11)		
13	Horizontal Scan Frequency (Line Rate) (kHz) (Item 8 × Item 12)		
14	Number of Character Times per Scan Line		
15	Character Clock Rate (MHz) (Item 13 × Item 14)		
16	Character Time (ns) (1 ÷ Item 15)		
17	Delay after Horizontal Blank start to Horizontal Sync start (Character Times)		
18	Horizontal Sync Width (Character Times)		
19	Dot Frequency (MHz) (Item 3 × Item 15)		
20	Dot Time (ns) (1 ÷ Item 19)		
21	Vertical Blanking Output Stop before start of Video (Number of Scan Lines) (Range = Item 4 – 1 line to 0 lines)		
22	Cursor Enable on all Scan Lines of a Row? (Yes or No) If not, which Line?		
23	Does the Horizontal Sync Pulse have Serrations during Vertical Sync? (Yes or No)		
24	Width of Line Buffer Clock logic "0" state within a Character Time (Number of Dot Time increments) (Typically ½ Item 3 rounded up)		
25	Serration Pulse Width, if used (Character Times) (See Figure 13)		
26	Horizontal Sync Pulse Active state logic level (1 or 0)		
27	Vertical Sync Pulse Active state logic level (1 or 0)		
28	Vertical Blanking Pulse Active state logic level (1 or 0)		

Video Monitor: Manufacturer and Model No. (For Engineering Reference)

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (soldering, 10 seconds)	300°C

Operating Conditions (Note 6)

	Min.	Max.	Units
V_{CC} , Supply Voltage	4.75	5.25	V
T_A , Ambient Temperature	0	+70	°C

Electrical Characteristics $V_{CC} = 5V \pm 5\%$, $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$ (Notes 2, 3, and 5)

Parameter		Conditions	Min.	Typ.	Max.	Units
V_{IH}	Logic "1" Input Voltage All Inputs Except X1, X2 $\overline{\text{RESET}}$ $\overline{\text{RESET}}$		2.0			V
			2.6			V
V_{IL}	Logic "0" Input Voltage All Inputs Except X1, X2				0.8	V
V_{HYS}	$\overline{\text{RESET}}$ Input Hysteresis			0.4		V
V_{clamp}	Input Clamp Voltage All Inputs Except X1, X2	$I_{IN} = -12\text{ mA}$		-0.8	-1.2	V
I_{IH}	Logic "1" Input Current A_0 - A_{11}	Enable Input = 0V, $V_{CC} = 5.25\text{V}$, $V_{IN} = 5.25\text{V}$		10	100	μA
		All Other Inputs Except X1, X2 $V_{CC} = 5.25\text{V}$, $V_{IN} = 5.25\text{V}$		2.0	20	μA
I_{IL}	Logic "0" Input Current A_0 - A_{11}	Enable Input = 0V, $V_{CC} = 5.25\text{V}$, $V_{IN} = 0.5\text{V}$		-20	-100	μA
		All Other Inputs Except X1, X2 $V_{CC} = 5.25\text{V}$, $V_{IN} = 0.5\text{V}$		-20	-100	μA
V_{OH}	Logic "1" Output Voltage	$I_{OH} = -100\mu\text{A}$	3.2	4.1		V
		$I_{OH} = -1\text{ mA}$	2.5	3.3		V
V_{OL}	Logic "0" Output Voltage	$I_{OL} = 5\text{ mA}$		0.35	0.5	V
I_{OS}	Output Short Circuit Current	$V_{CC} = 5\text{V}$, $V_{OUT} = 0\text{V}$ (Note 4)	10	40	100	mA
I_{CC}	Power Supply Current (Note 10)	$V_{CC} = 5.25\text{V}$		220	300	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min./max. limits apply across the 0°C to $+70^\circ\text{C}$ temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0\text{V}$ and are intended for reference only.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max. or min. are so classified on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: Electrical specifications do not apply to pin 17, external char/line clock, as this pin is used for production testing only.

Note 6: Functional operation of device is not guaranteed when operated beyond specified operating condition limits.

Switching Characteristics $V_{CC} = 5.0V \pm 5\%$, $T_A = 25^\circ\text{C}$ (Note 7)

Parameter		Load Circuit	Notes	Min.	Typ.	Max.	Units
Symmetry	Dot Rate Clock Output High Symmetry With Crystal Control	1		50% - 4	50% - 2	50% + 1	ns
t_{pd1}	X1 Input to Dot Rate Clock Output Positive Edge	1			17	22	ns
t_{pd0}	X1 Input to Dot Rate Clock Output Negative Edge	1			21	26	ns
t_{D1}	Dot Clock to Load Video Shift Register Negative Edge	1			6.0	10	ns
t_{D2}	Dot Clock to Load Video Shift Register Positive Edge	1			11	15	ns
t_{D3}	Dot Clock to Latch Character Generator Positive Edge	1			8.0	13	ns
t_{D4}	Dot Clock to Latch Character Generator Negative Edge	1			6.0	10	ns

Switching Characteristics (Cont'd.) $V_{CC} = 5.0V \pm 5\%$, $T_A = 25^\circ C$ (Note 7)

Parameter		Load Circuit	Notes	Min.	Typ.	Max.	Units
$t_{D2-t_{D3}}$	Latch Character Generator Positive Edge to Load Video Shift Register Positive Edge	1		0	3.0		ns
t_{D5}	Dot Clock to Line Buffer Clock Negative Edge	1			23	35	ns
t_{PW1}	Line Buffer Clock Pulse Width	1	8,9	N(DT)	N(DT)+8	N(DT)+12	ns
t_{D6}	Dot Clock to Cursor Enable Output Transition	1			24	36	ns
t_{D7}	Dot Clock to Valid Address Output	1			15	25	ns
t_{D8_0}	Latch Character Generator to Line Rate Clock Neg. Transition	1	8,10		425 + DT	500 + DT	ns
t_{D8_1}	Latch Character Generator to Line Rate Clock Pos. Transition	1	8,10		300 + DT	400 + DT	ns
t_{D9_0}	Latch Character Generator to Clear Line Counter Neg. Transition	1	8,10		525 + DT	700 + DT	ns
t_{D9_1}	Latch Character Generator to Clear Line Counter Pos. Transition	1	8,10		290 + DT	400 + DT	ns
$t_{D8_1-t_{D9_1}}$	Clear Line Counter Pos. Transition to Line Rate Clock Pos. Transition	1	10		10	60	ns
t_{D10}	Line Rate Clock to Line Counter Output Transition	1			60	120	ns
t_{D11}	Line Rate Clock to Line Buffer Recirculate Enable Transition	1			195	300	ns
t_{D12}	Line Rate Clock to Vertical Blanking Transition	1			160	300	ns
t_{D13}	Line Rate Clock to Vertical Sync Transition	1			220	300	ns
t_{D14}	Latch Character Generator to Horizontal Sync Transition	1			96	150	ns
t_{S1}	Register Select Set-up Before Register Load Negative Edge			0			ns
t_{H1}	Register Select Hold After Register Load Positive Edge			0			ns
t_{S2}	Valid Address Input Set-Up Before Register Load Positive Edge			250			ns
t_{H2}	Valid Address Hold Time After Register Load Positive Edge			0			ns
t_{PW2}	Register Load Required Pulse Width			150	65		ns
t_{LZ}, t_{HZ}	Delay from Enable Input to Address Output High Impedance State from Logic "0" and Logic "1"	2			15	30	ns
t_{ZL}, t_{ZH}	Delay from Enable Input to Logic "0" and Logic "1" from Address Output High Impedance State	2			17	30	ns

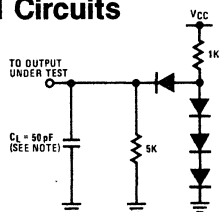
Note 7: Typical values are for $V_{CC} = 5.0V$ and $T_A = 25^\circ C$ and are meant for reference only.

Note 8: "DT" denotes dot rate clock period time, item 20 from option format table.

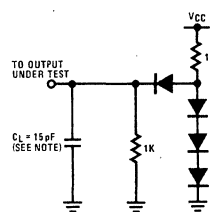
Note 9: "N" denotes value of item 24 from option format table.

Note 10: Revised since last issue.

Switching Load Circuits



Load Circuit 1



Load Circuit 2

Note: C_L includes probe and jig capacitance. All diodes are 1N914 or equivalent.

Switching Waveforms

$$\text{SYMMETRY} = \frac{T_H}{T_P} \times 100\%$$

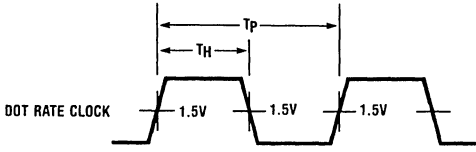


Figure 7. Dot Rate Clock Output Waveform Symmetry with Crystal Control

$$t_r = t_f \leq 10 \text{ ns}$$

$$X2 (\text{PIN } 21) = \text{OPEN}$$

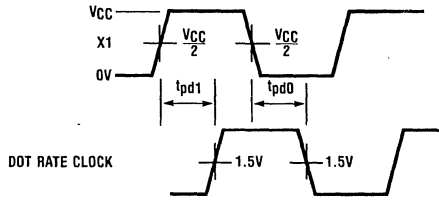
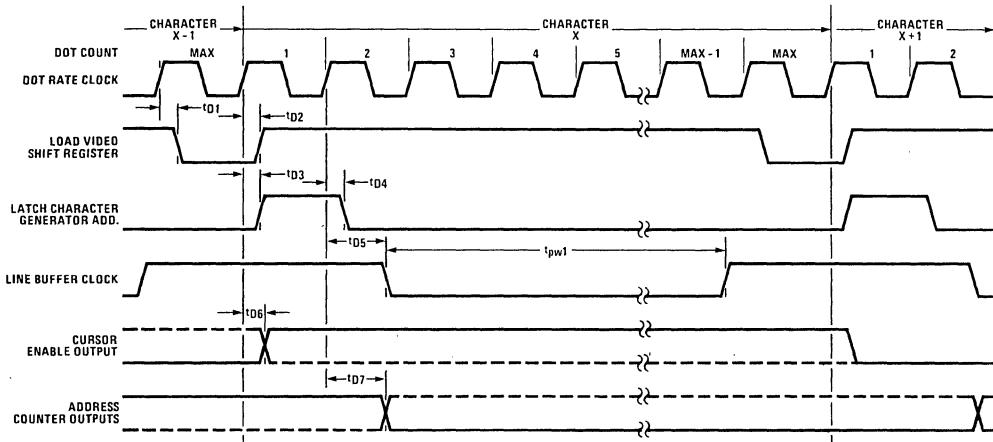
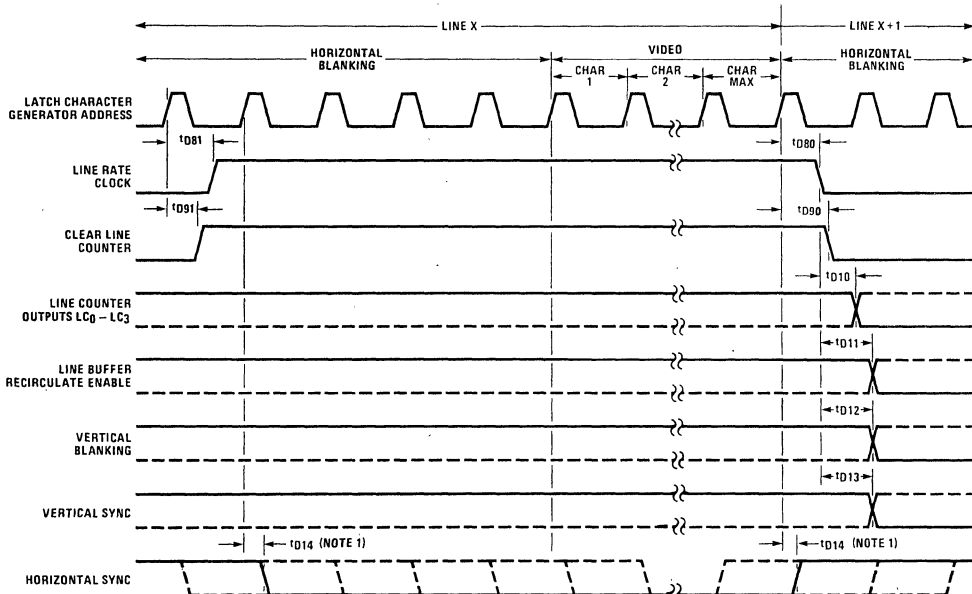


Figure 8. X1 Input to Dot Rate Clock Output Propagation Delay



Note 1: All measurement points are 1.5V

Figure 9. Dot/Character Rate Timing

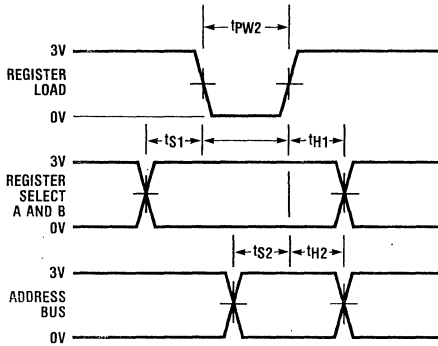


Note 1: Actual polarity and position of the horizontal sync start and stop points is a function of the particular device format.

Note 2: All measurement points are 1.5V.

Figure 10. Character/Line Rate Timing

Switching Waveforms (cont'd)



Note 1: All measurement points are 1.5V.

Note 2: $t_r = t_f \leq 10$ ns.

Note 3: Address enable (pin 37) = 0V.

Figure 11. Register Select and Load Waveforms

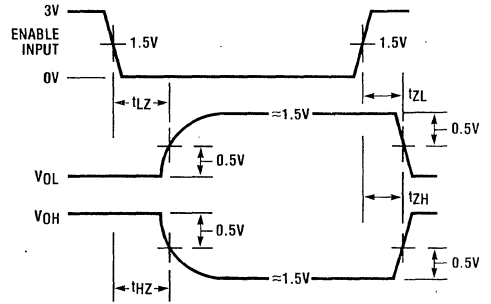
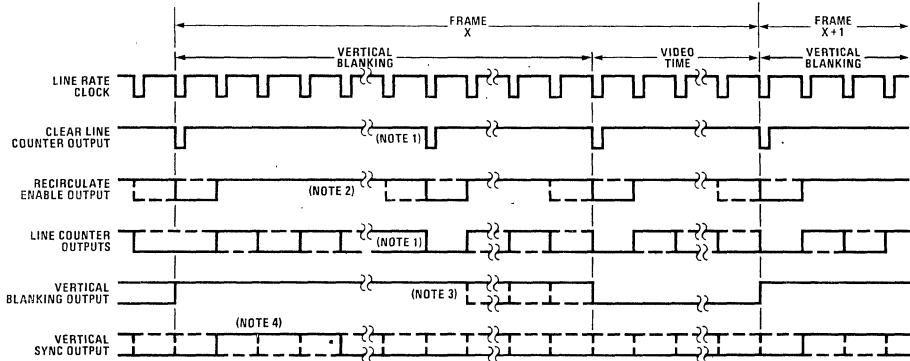


Figure 12. Address Output Enable/Disable Waveforms

Timing Diagrams



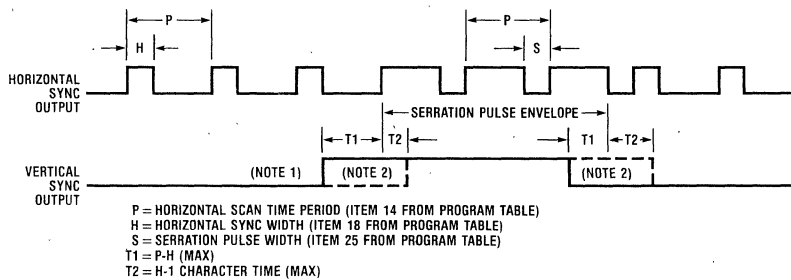
Note 1: One full row before start of video the line counter is set to zero state — this provides line counter synchronization in cases where the number of lines in vertical blanking are not even multiples of the number of lines per row.

Note 2: The position of the line buffer recirculate enable logic low level is a function of the logic level of the address mode input (see Table 3).

Note 3: The stop point of the vertical blanking output active signal is a function of device type or custom option, and will always be within one row prior to video.

Note 4: The transition start and stop points of the vertical sync output signal are a function of device type or custom option.

Figure 14. Line/Frame Rate Functional Diagram

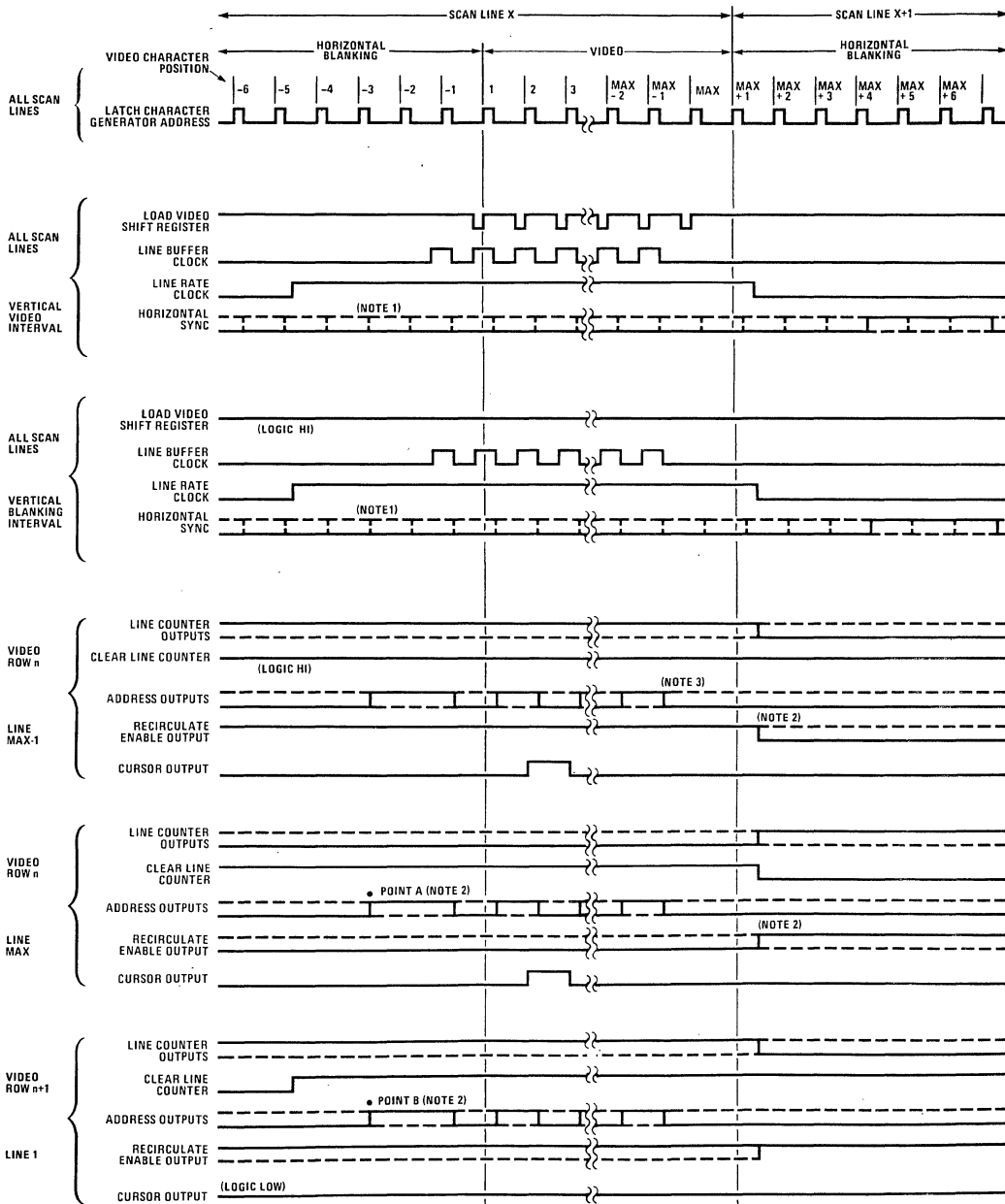


Note 1: The vertical sync transition point is always coincident with the beginning of horizontal blanking.

Note 2: T1 and T2 intervals represent the range of alignment offset between the vertical sync pulse and the serration pulse envelope and is a function of the horizontal sync position with respect to the beginning of horizontal blanking.

Figure 15. Serration Pulse Format

Timing Diagrams (cont'd)



Note 1: The horizontal sync output start and stop point positions are a function of device type or custom option.

Note 2: The position of the recirculate enable output logic "0" level is dependent on the state of the address mode input. When address mode = "0", recirculate enable occurs on the max. line of a character row (solid line) and the address counter outputs roll over to the new row address at point A. When address mode = "1", recirculate enable occurs on the first line of a character row (dashed line) and the address counter outputs roll over to the new row address at point B.

Note 3: The address counter outputs clock to the address of the last character of a video row plus 1. This address is then held during the horizontal blanking interval until video minus three character times. At this point the outputs are modified to the contents of the Row Start Register (RSR).

Figure 13. Character/Line Rate Functional Diagram

Applications

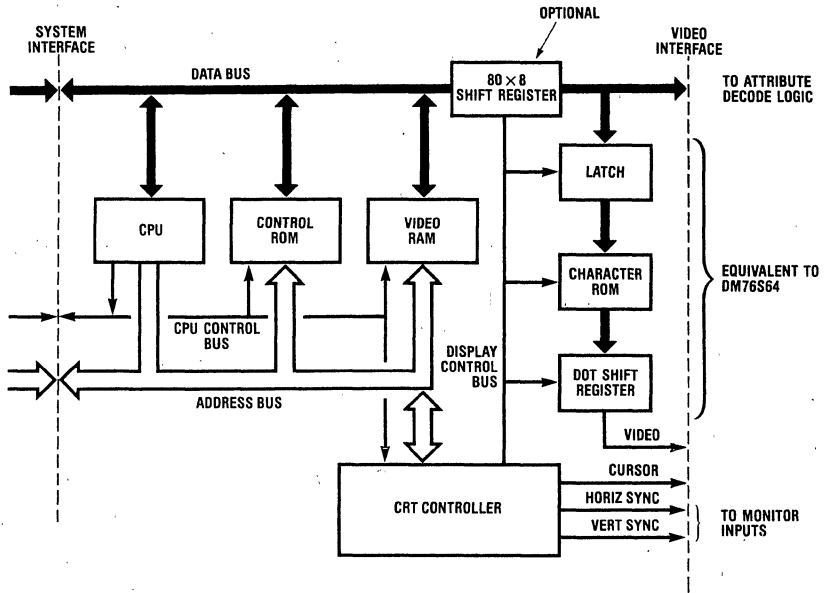


Figure 16. General System Block Diagram

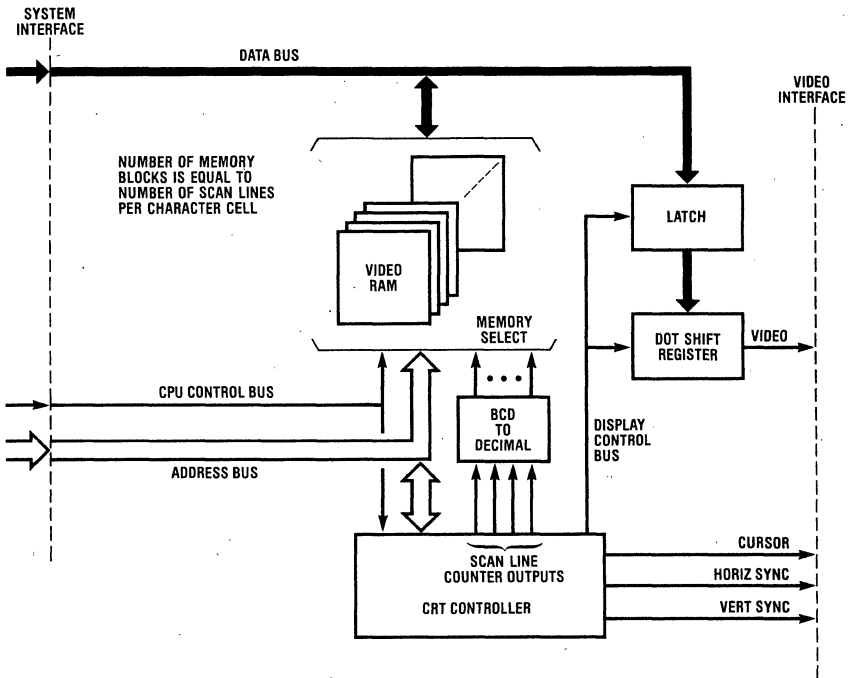


Figure 17. Dot-By-Dot Graphics Block Diagram

DP8350 CRT Controller

Table 6. Characteristic Format

Item No.	Parameter	Value	
1	Character Font Size (Reference Only)	Dots per Character (Width)	
2		Scan Lines per Character (Height)	
3	Character Field Cell Size	Dots per Character (Width)	
4		Scan Line per Character (Height)	
5	Number of Video Characters per Row		80
6	Number of Video Character Rows per Frame		24
7	Number of Video Scan Lines (Item 4 × Item 6)		240
8	Frame Refresh Rate (Hz)	f1 = 60	f0 = 50
9	Delay after Vertical Blank start to start of Vertical Sync (Number of Scan Lines)	4	30
10	Vertical Sync Width (Number of Scan Lines)	10	10
11	Interval between Vertical Blank start and start of Video (Number of Scan Lines of Video Blanking)	20	72
12	Total Scan Lines per Frame (Item 7 + Item 11)	260	312
13	Horizontal Scan Frequency (Line Rate) (Item 8 × Item 12)	15.6 kHz	
14	Number of Character Times per Scan Line	100	
15	Character Clock Rate (Item 13 × Item 14)	1.56 MHz	
16	Character Time (1 ÷ Item 15)	641 ns	
17	Delay after Horizontal Blank start to Horizontal Sync start (Character Times)	0	
18	Horizontal Sync Width (Character Times)	43	
19	Dot Frequency (Item 3 × Item 15)	10.92 MHz	
20	Dot Time (1 ÷ Item 19)	91.6 ns	
21	Vertical Blanking Output Stop before start of Video (Number of Scan Lines)	1	
22	Cursor Enable on all Scan Lines of a Row? (Yes or No)	Yes	
23	Does the Horizontal Sync Pulse have Serrations during Vertical Sync? (Yes or No)	No	
24	Width of Line Buffer Clock logic "0" state within a Character Time (Number of Dot Time increments)	4	
25	Serration Pulse Width, if used (Character Times)	—	
26	Horizontal Sync Pulse Active state logic level (1 or 0)	1	
27	Vertical Sync Pulse Active state logic level (1 or 0)	0	
28	Vertical Blanking Pulse Active state logic level (1 or 0)	1	

Video Monitor Format: Ball Brothers TV-12, TV-120 or Equivalent.

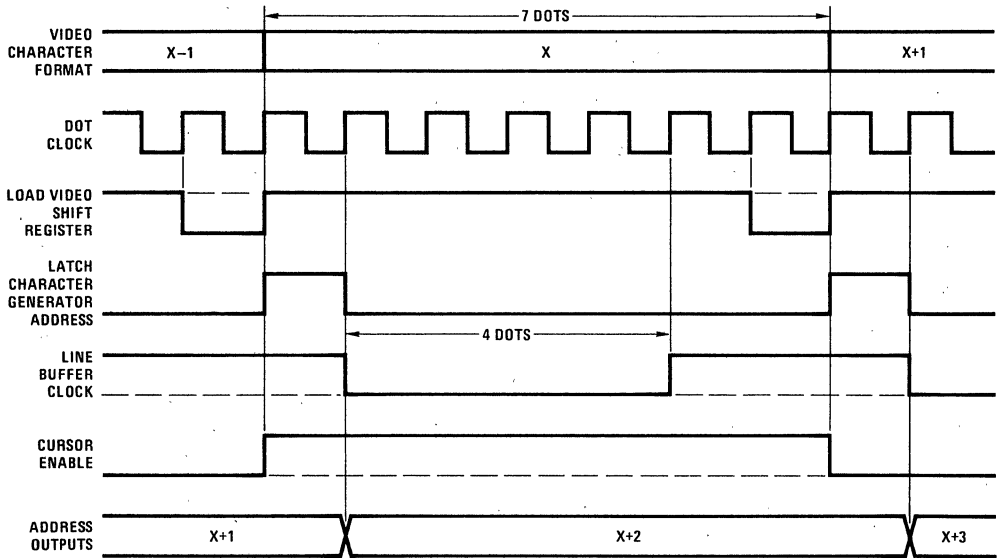


Figure 18. DP8350 Video Character Signals

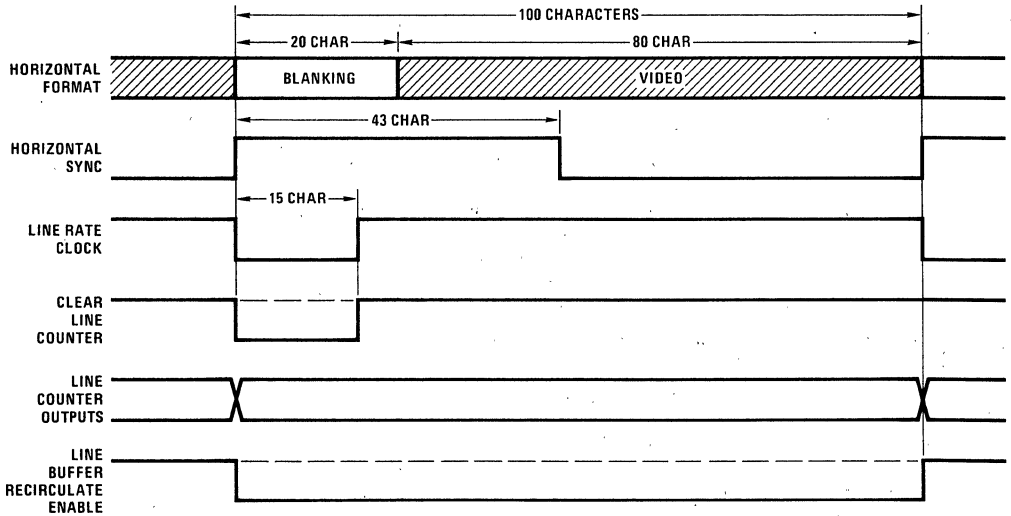


Figure 19. DP8350 Scan Line Signals

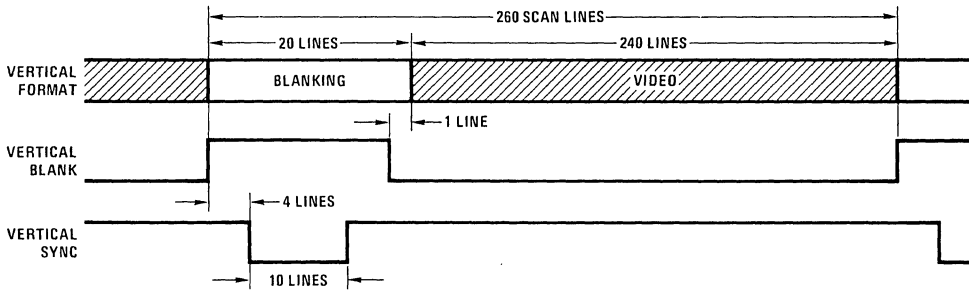


Figure 20. DP8350 60 Hz Refresh Rate Frame Signals

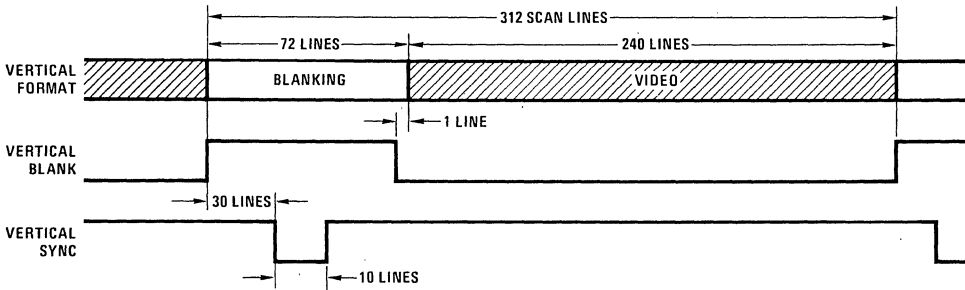


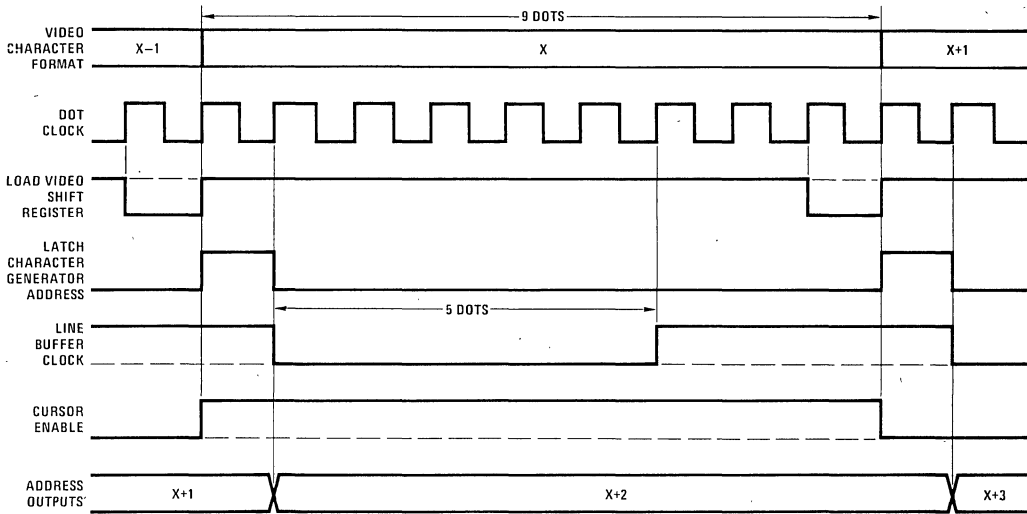
Figure 21. DP8350 50 Hz Refresh Rate Frame Signals

DP8352 CRT Controller

Table 7. Characteristic Format

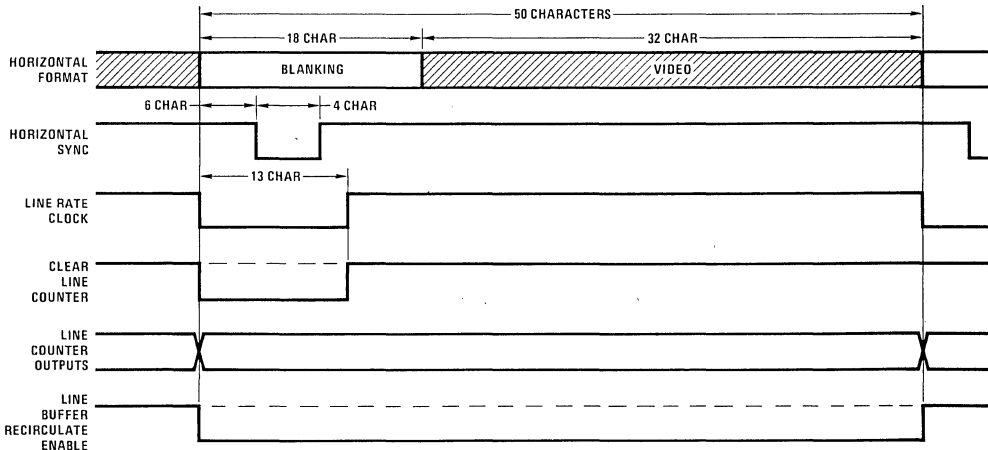
Item No.	Parameter	Value	
1	Character Font Size (Reference Only)	Dots per Character (Width)	
2		Scan Lines per Character (Height)	
3	Character Field Cell Size	Dots per Character (Width)	
4		Scan Line per Character (Height)	
5	Number of Video Characters per Row		32
6	Number of Video Character Rows per Frame		16
7	Number of Video Scan Lines (Item 4 × Item 6)		192
8	Frame Refresh Rate (Hz)	f1 = 60	f0 = 50
9	Delay after Vertical Blank start to start of Vertical Sync (Number of Scan Lines)	27	53
10	Vertical Sync Width (Number of Scan Lines)	3	3
11	Interval between Vertical Blank start and start of Video (Number of Scan Lines of Video Blanking)	68	120
12	Total Scan Lines per Frame (Item 7 + Item 11)	260	312
13	Horizontal Scan Frequency (Line Rate) (Item 8 × Item 12)	15.6kHz	
14	Number of Character Times per Scan Line	50	
15	Character Clock Rate (Item 13 × Item 14)	0.78MHz	
16	Character Time (1 ÷ Item 15)	1282ns	
17	Delay after Horizontal Blank start to Horizontal Sync start (Character Times)	6	
18	Horizontal Sync Width (Character Times)	4	
19	Dot Frequency (Item 3 × Item 15)	7.02MHz	
20	Dot Time (1 ÷ Item 19)	142.4ns	
21	Vertical Blanking Output Stop before start of Video (Number of Scan Lines)	0	
22	Cursor Enable on all Scan Lines of a Row? (Yes or No)	Yes	
23	Does the Horizontal Sync Pulse have Serrations during Vertical Sync? (Yes or No)	Yes	
24	Width of Line Buffer Clock logic "0" state within a Character Time (Number of Dot Time increments)	5	
25	Serration Pulse Width, if used (Character Times)	4	
26	Horizontal Sync Pulse Active state logic level (1 or 0)	0	
27	Vertical Sync Pulse Active state logic level (1 or 0)	0	
28	Vertical Blanking Pulse Active state logic level (1 or 0)	1	

Video Monitor Format: RS-170-Compatible (Standard American TV).



NOTE: DASHED LINES IN WAVEFORMS DENOTE INACTIVE STATE LOGIC LEVELS.

Figure 22. DP8352 Video Character Signals



NOTE: DASHED LINES IN WAVEFORMS DENOTE INACTIVE STATE LOGIC LEVELS.

Figure 23. DP8352 Scan Line Signals

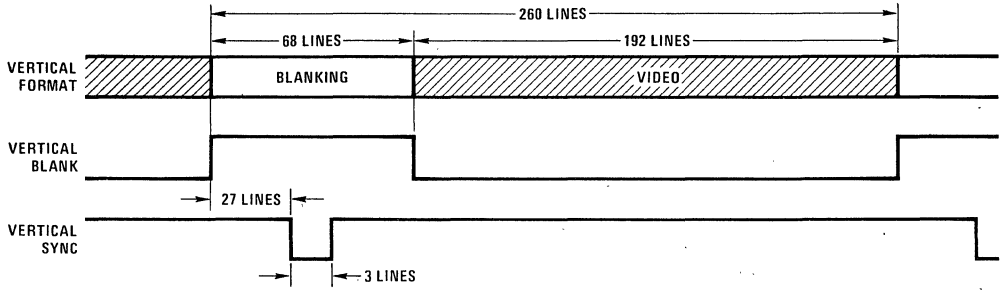


Figure 24. DP8352 60 Hz Refresh Rate Frame Signals

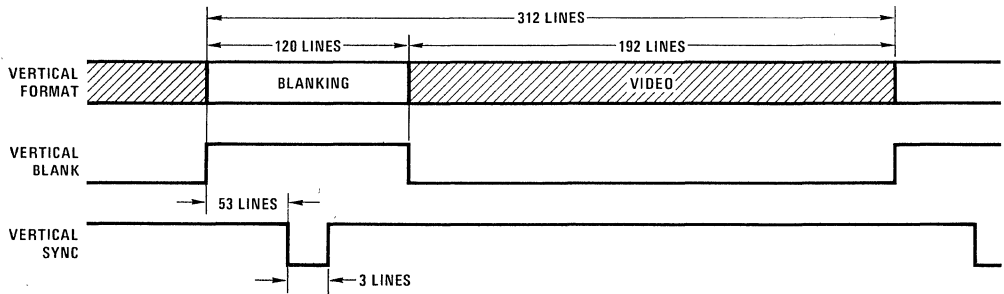


Figure 25. DP8352 50 Hz Refresh Rate Frame Signals

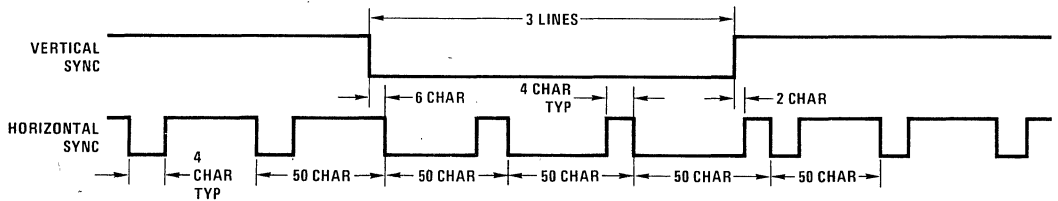


Figure 26. DP8352 Serration Pulse Format

DP8353 CRT Controller

Table 8. Characteristic Format

Item No.	Parameter	Value	
1	Character Font Size (Reference Only)	Dots per Character (Width)	
2		Scan Lines per Character (Height)	
3	Character Field Cell Size	Dots per Character (Width)	
4		Scan Line per Character (Height)	
5	Number of Video Characters per Row	80	
6	Number of Video Character Rows per Frame	25	
7	Number of Video Scan Lines (Item 4 × Item 6)	300	
8	Frame Refresh Rate (Hz)	f1 = 60	f0 = 50
9	Delay after Vertical Blank start to start of Vertical Sync (Number of Scan Lines)	0	32
10	Vertical Sync Width (Number of Scan Lines)	3	3
11	Interval between Vertical Blank start and start of Video (Number of Scan Lines of Video Blanking)	20	84
12	Total Scan Lines per Frame (Item 7 + Item 11)	320	384
13	Horizontal Scan Frequency (Line Rate) (Item 8 × Item 12)	19.20 kHz	
14	Number of Character Times per Scan Line	102	
15	Character Clock Rate (Item 13 × Item 14)	1.9584 MHz	
16	Character Time (1 ÷ Item 15)	510.6 ns	
17	Delay after Horizontal Blank start to Horizontal Sync start (Character Times)	5	
18	Horizontal Sync Width (Character Times)	9	
19	Dot Frequency (Item 3 × Item 15)	17.6256 MHz	
20	Dot Time (1 ÷ Item 19)	56.7 ns	
21	Vertical Blanking Output Stop before start of Video (Number of Scan Lines)	1	
22	Cursor Enable on all Scan Lines of a Row? (Yes or No)	Yes	
23	Does the Horizontal Sync Pulse have Serrations during Vertical Sync? (Yes or No)	No	
24	Width of Line Buffer Clock logic "0" state within a Character Time (Number of Dot Time increments)	5	
25	Serration Pulse Width, if used (Character Times)	—	
26	Horizontal Sync Pulse Active state logic level (1 or 0)	1	
27	Vertical Sync Pulse Active state logic level (1 or 0)	1	
28	Vertical Blanking Pulse Active state logic level (1 or 0)	1	

Video Monitor Format: Motorola M3003 or Equivalent.

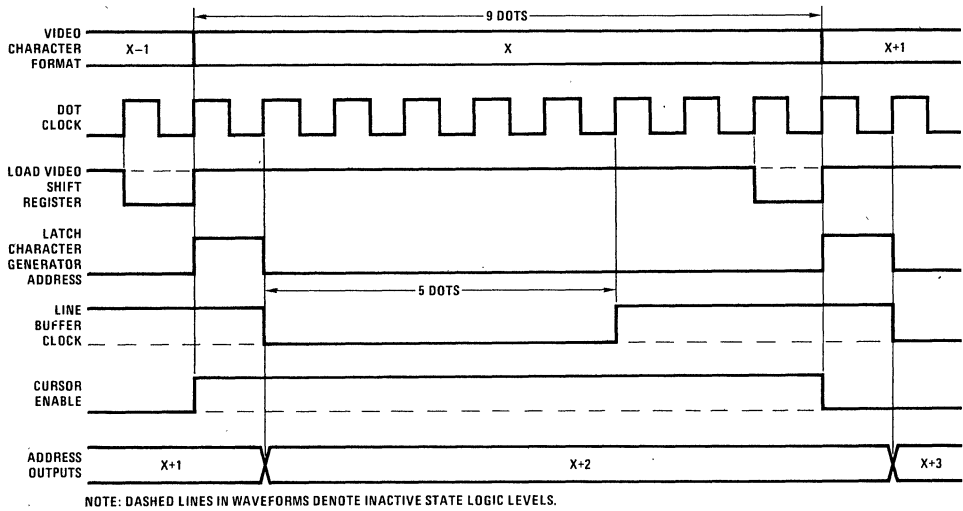


Figure 27. DP8353 Video Character Signals

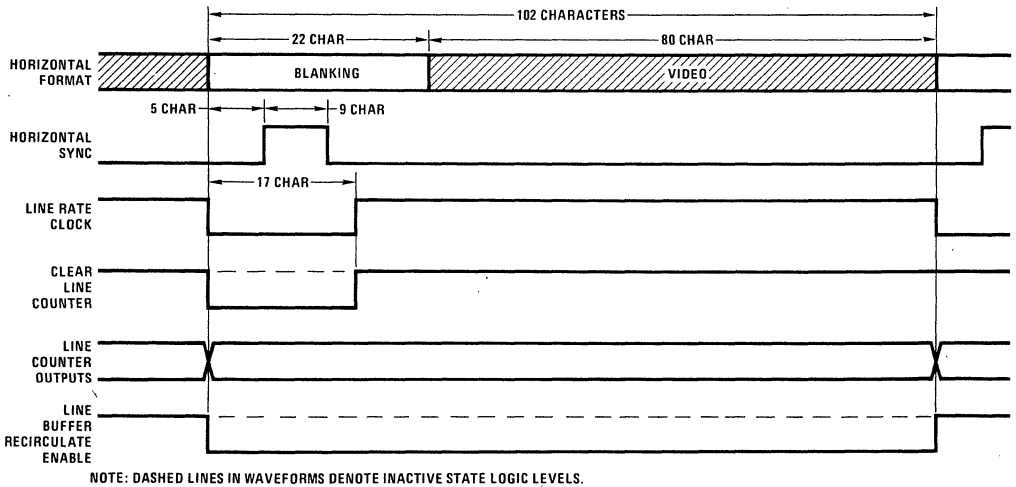


Figure 28. DP8353 Scan Line Signals

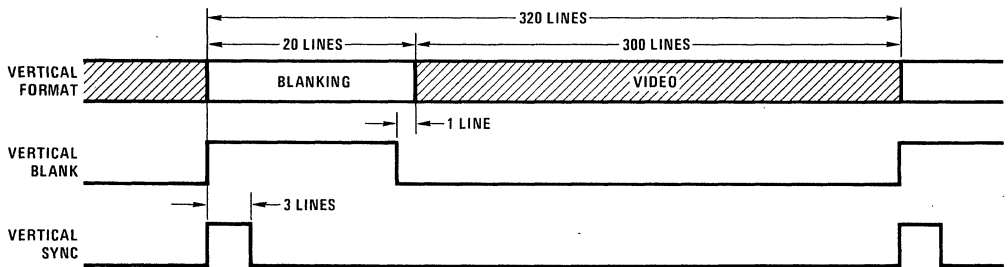


Figure 29. DP8353 60 Hz Refresh Rate Frame Signals

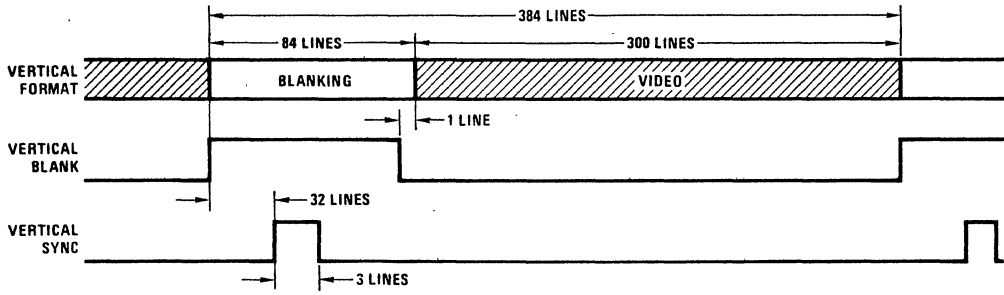


Figure 30. DP8353 50 Hz Refresh Rate Frame Signals

A Low Component Count Video Data Terminal Using the DP8350 CRT Controller and the INS8080 CPU

National Semiconductor
Application Note 199
Al Brilliot
August 1978



INTRODUCTION

The DP8350 is an I²L - LS technology integrated circuit, designed to provide all control signals for a cathode ray tube (CRT) display system. This application note explains a system using the DP8350 and the INS8080 microprocessor. The design philosophy shows how the DP8350 interfaces to the INS8080, completing the function of a video data terminal with a minimum component count. After reading and understanding this application note the reader will realize the ease and flexibility of designing video terminals with the DP8350*. To thoroughly understand this application note the reader must be familiar with the DP8350 and the INS8080 microprocessor.

The video data terminal described is divided into the following sections, (Figure 1).

The DP8350 CRT controller (CRTC).

The 8080 μ P system which includes ROM, RAM, interrupt instruction port, oscillator, and control support chips.

The character generator.

The communication element.

The keyboard and baud rate select ports.

THE CRTC

The DP8350 generates all the required control and timing signals for displaying video information on the video monitor. Here is a summary of the controller's functions:

Dot clock, control, and counter outputs for the character generator.

Bidirectional RAM address refresh counter for refreshing the video RAM and allowing microprocessor loading to the internal DP8350 registers.

Direct drive horizontal and vertical sync signal outputs.

Direct cursor address location output. The cursor is internally delayed or pipelined, allowing for the access time of video RAM and the character generator ROM, (Figure 1).

THE CPU

The microprocessor provides CRTC, operator, and external machine control for the system. When the CRT controller is not actively refreshing the video RAM, (i.e., during vertical retrace or blank scan lines), the microprocessor is enabled for system housekeeping, (Figure 2). This method of multiplexing the RAM with

*The DP8350 is equivalent to the INS8276

the CPU and the CRTC eliminates the need for line buffers.

THE CHARACTER GENERATOR

The character generator consists of 3 elements: an address latch to hold the input address to the character ROM allowing for the access time of the ROM; the character ROM that stores the ASCII character in a form for parallel to serial conversion by the shift register; the shift register converts the character ROMs parallel output to serial form. The serial output from the shift register is the true video output, modulating the video monitors electron beam which writes characters on the screen. All of the 3 elements of the character generator are combined in the DM8678, (Figure 3). The DP8350 CRTC provides all the control signals for the DM8678.

THE COMMUNICATION ELEMENT

The INS8250 is the asynchronous communication element (ACE) for the data terminal. The ACE allows the CPU portion of the data terminal communication with peripherals or host computers at the correct baud rate, (Figure 1). The ACE is programmed by the CPU to send and receive serial data at the standard baud rates from 110 to 4800 baud. The ACE, in conjunction with the DS1488 and DS1489 line drivers and receivers, also provides full RS232C synchronous communication if higher baud rates are desired. System communication speed must always be considered to insure the baud rate does not exceed the time required for the CPU to process a data byte. Asynchronous communication at baud rates higher than 4800 are possible by adding a line buffer.

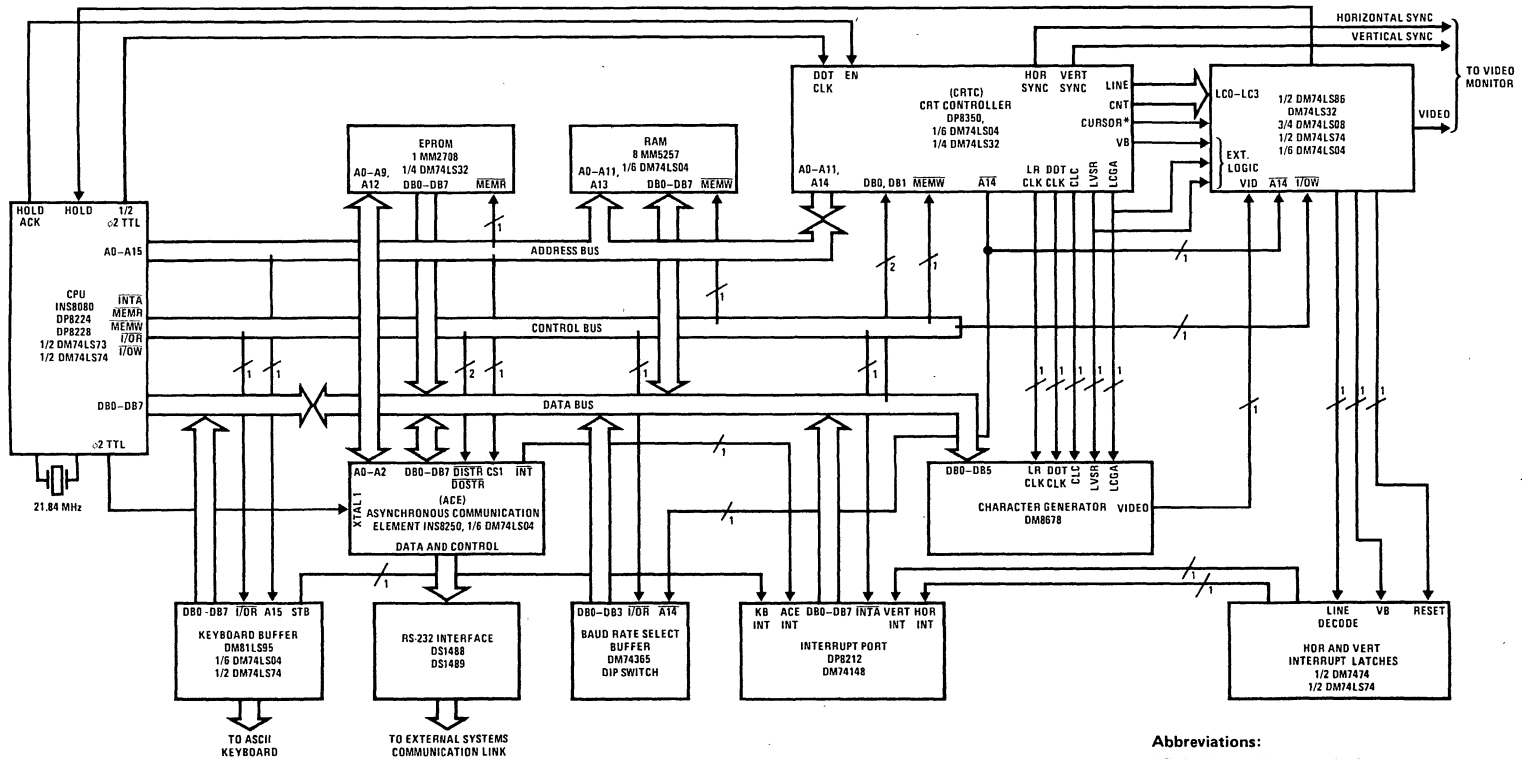
SYSTEM INITIALIZATION

Application of the terminal's power supply resets the microprocessor, the communication element, and the CRT controller. Resetting the ACE is necessary to clear the interrupt. Resetting the CRTC is not absolutely necessary since the microprocessor loads the cursor and top of page registers in the initialization routine.

Following the reset all interrupts are disabled to avoid unwanted interrupts from the CRTC, ACE, or I/O ports. Refer to the initialization routine in the flowchart.

The stack pointer is loaded to the bottom of scratch pad RAM (3FFFH) for use as the register save pointer, (Figure 4).

The entire RAM is written with ASCII spaces generating a cleared screen. After completion of the screen clear loop the CPU writes 000H to the cursor and the top of page registers in the DP8350 CRTC. The routine homes the cursor to the upper left corner of the screen. The top of page register was loaded with 000H, therefore, the video RAM is refreshed by the CRTC from that starting address to the last address on the screen of video RAM (1920 characters).



*The cursor is internally pipelined by the CRTC to allow for access time of the RAM and the character generator.

Abbreviations:

LR CLK	Line rate clock
CLC	Clear line counter
LVSR	Load video shift register
LCCA	Latch character generator address
Line CNT	Line counter
EN	Enable
VID	Video
KB INT	Keyboard interrupt
VB	Vertical blanking

FIGURE 1. Video Data Terminal Detailed Block Diagram

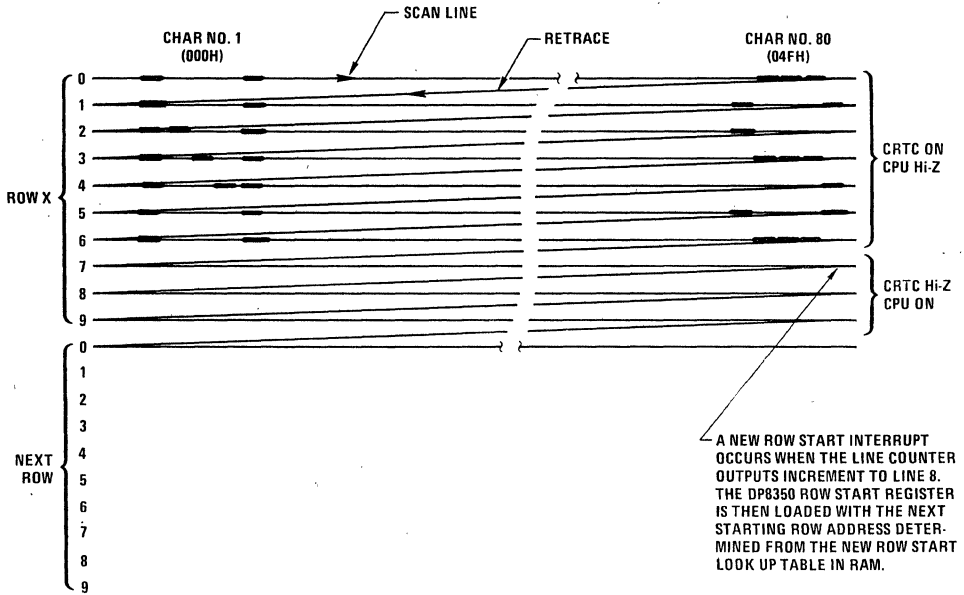


FIGURE 2. Row Start Interrupting and Multiplexing the INS8080 with the DP8350

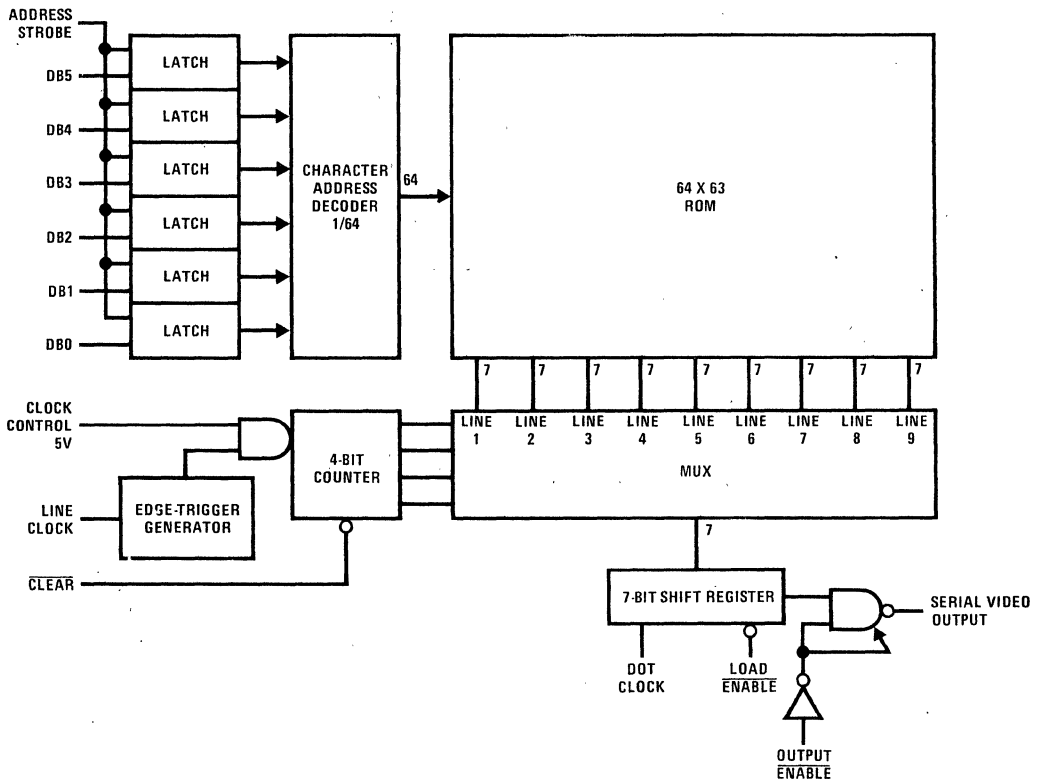


FIGURE 3. DM8678 Character Generator Block Diagram

The CPU is ready to perform the communication element (ACE) load routine. First, the baud rate divisor for the ACE must be determined. The baud rate select switch is read providing a code which corresponds to the appropriate 16-bit divisor for the ACE. This divisor determines the baud rate at which the ACE will communicate. Any additional programming requirements needed for the ACE to communicate with host computer systems could also be done at this time. The software in this system does not contain any additional programming for the ACE. There are many programming modes related to the ACE. Details of these modes are beyond the scope of this application note.

The row start look-up table, (Figure 5), is loaded up by a simple algorithm that loads and adds the data for referencing a row number to that row's starting address. The reference table, (Figure 6), is initialized next by direct loading. This table provides the CPU with top of page, bottom of page, next row load, cursor row, and scratch row numbers for system housekeeping.

Finally, the new row start and vertical interrupt latches are cleared, (Figure 7). The register pointers are loaded and the CPU is forced in a wait loop with interrupts enabled.

NON-SEQUENTIAL ADDRESSING

The data terminal described here was designed for non-sequential starting row addressing. In many systems sequential row addressing is used. If a character row consists of 10 scan lines the RAM is addressed 10 repetitive times from 000H through 04FH, (Figure 2). The next row is refreshed in the same manner from 050H to 09FH. The starting row address is sequential 000H, 050H, 0A0H—E0H for row numbers 0H, 1H, 2H,—2FH, respectively. Non-sequential row addressing would be equivalent to 050H, 000H, 0A0H—E0H for row numbers 1H, 0H,—2FH, respectively, (Figure 4).

In conjunction with the CPU, non-sequential row addressing is quite easily accomplished with the DP8350 since this is one of the features designed into the part. Accomplishing this task basically requires the following sequence of events. Assume the CRTC has finished writing a video row in the middle of the monitor's screen. This system has a 5 x 7 character font in a 7 x 10 field, (Figure 2). At the completion of the last video scan line 7 the CRTC line counters continue to count the last 3 lines. Video is not present since the character is only 7 scan lines high. The blank scan lines are 7, 8, and 9 permitting the CRTC address outputs to be TRI-STATED®, allowing the CPU to run. When the line counter outputs increment to scan line 8 an interrupt signals the CPU. The interrupt occurring is the new row start interrupt. The interrupt routine fetches the next CRTC row number from the reference table (Figure 6). This number is converted to the new starting row address, explained later, and loaded to the CRTC row start register. The CPU finishes the routine by clearing the interrupt, readying itself for the next new row start interrupt. The entire routine takes 1 scan line of time, approximately 64 μs. The CRTC continues to scan the video RAM from that new starting address on for the next 7 repetitive scan lines of the next row. Many advantages become apparent using the non-sequential addressing scheme. Scrolling up or down with the cursor always on the screen may be done

faster and easier from a hardware/software standpoint. Exchanging one row with another row is fast since it is not necessary to rewrite the video RAM. Row swapping is useful for higher end terminals requiring row editing functions.

ADDRESS MAP

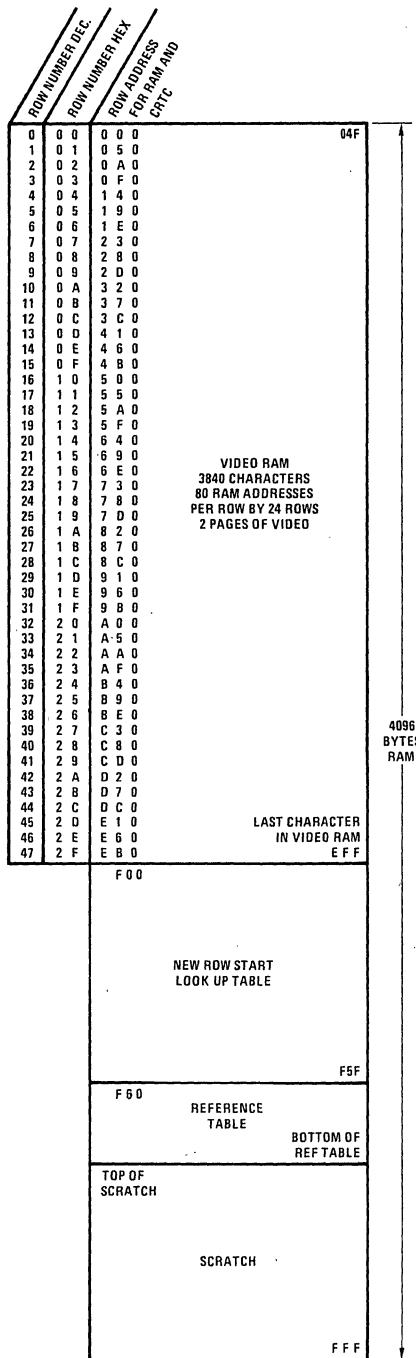


FIGURE 4. RAM Organization

ROW NUMBER		NRS HIGH		NRS LOW	
DEC	HEX	ADDRESS	ROW DATA	ADDRESS	ROW DATA
0	0 0	3 F 0 0	3 0	3 F 3 0	0 0
1	0 1	3 F 0 1	3 0	3 F 3 1	5 0
2	0 2	3 F 0 2	3 0	3 F 3 2	A 0
3	0 3	3 F 0 3	3 0	3 F 3 3	F 0
4	0 4	3 F 0 4	3 1	3 F 3 4	4 0
5	0 5	3 F 0 5	3 1	3 F 3 5	9 0
6	0 6	3 F 0 6	3 1	3 F 3 6	E 0
7	0 7	3 F 0 7	3 2	3 F 3 7	3 0
8	0 8	3 F 0 8	3 2	3 F 3 8	8 0
9	0 9	3 F 0 9	3 2	3 F 3 9	D 0
10	0 A	3 F 0 A	3 3	3 F 3 A	2 0
11	0 B	3 F 0 B	3 3	3 F 3 B	7 0
12	0 C	3 F 0 C	3 3	3 F 3 C	C 0
13	0 D	3 F 0 D	3 4	3 F 3 D	1 0
14	0 E	3 F 0 E	3 4	3 F 3 E	6 0
15	0 F	3 F 0 F	3 4	3 F 3 F	B 0
16	1 0	3 F 1 0	3 5	3 F 4 0	0 0
17	1 1	3 F 1 1	3 5	3 F 4 1	5 0
18	1 2	3 F 1 2	3 5	3 F 4 2	A 0
19	1 3	3 F 1 3	3 5	3 F 4 3	F 0
20	1 4	3 F 1 4	3 6	3 F 4 4	4 0
21	1 5	3 F 1 5	3 6	3 F 4 5	9 0
22	1 6	3 F 1 6	3 6	3 F 4 6	E 0
23	1 7	3 F 1 7	3 7	3 F 4 7	3 0

ROW NUMBER		NRS HIGH		NRS LOW	
DEC	HEX	ADDRESS	ROW DATA	ADDRESS	ROW DATA
24	1 8	3 F 1 8	3 7	3 F 4 8	8 0
25	1 9	3 F 1 9	3 7	3 F 4 9	D 0
26	1 A	3 F 1 A	3 8	3 F 4 A	2 0
27	1 B	3 F 1 B	3 8	3 F 4 B	7 0
28	1 C	3 F 1 C	3 8	3 F 4 C	C 0
29	1 D	3 F 1 D	3 9	3 F 4 D	1 0
30	1 E	3 F 1 E	3 9	3 F 4 E	6 0
31	1 F	3 F 1 F	3 9	3 F 4 F	B 0
32	2 0	3 F 2 0	3 A	3 F 5 0	0 0
33	2 1	3 F 2 1	3 A	3 F 5 1	5 0
34	2 2	3 F 2 2	3 A	3 F 5 2	A 0
35	2 3	3 F 2 3	3 A	3 F 5 3	F 0
36	2 4	3 F 2 4	3 B	3 F 5 4	4 0
37	2 5	3 F 2 5	3 B	3 F 5 5	9 0
38	2 6	3 F 2 6	3 B	3 F 5 6	E 0
39	2 7	3 F 2 7	3 C	3 F 5 7	3 0
40	2 8	3 F 2 8	3 C	3 F 5 8	8 0
41	2 9	3 F 2 9	3 C	3 F 5 9	D 0
42	2 A	3 F 2 A	3 D	3 F 5 A	2 0
43	2 B	3 F 2 B	3 D	3 F 5 B	7 0
44	2 C	3 F 2 C	3 D	3 F 5 C	C 0
45	2 D	3 F 2 D	3 E	3 F 5 D	1 0
46	2 E	3 F 2 E	3 E	3 F 5 E	6 0
47	2 F	3 F 2 F	3 E	3 F 5 F	B 0

FIGURE 5. New Row Start Look Up Table

FUNCTION	ADDRESS	DATA	INITIALIZED DATA
Last Row #	3F60	XY	17
8080 Row #	3F61	XY	00
First Row #	3F62	XY	00
Character #	3F63	XY	00
CRTC Row #	3F64	XY	00
Row Save #	3F65	XY	00
Temp. 1	3F66	XY	00
Temp. 2	3F67	XY	00

FIGURE 6. Reference Table

COMMAND	FUNCTION
OUT 40	Clear new row start and vertical interrupt latches
IN 80	Read keyboard
IN 40	Read baud rate select switch

FIGURE 7. Input/Output Space

DEVICE	ADDRESS*
ROM	0000 to 0FFF
RAM	3000 to 3FFF
CRTC	5000 to 5FFF
ACE	9000 to 9007

*Direct device selecting was used to minimize the system component count.

FIGURE 8. CPU Addressing Space

ROW NUMBER		NRS HIGH		NRS LOW	
DEC	HEX	ADDRESS	ROW DATA	ADDRESS	ROW DATA
32	2 0	3 F 2 0	3 A	3 F 5 0	0 0

Row Start Address for Row 20H.

3XXX Selects RAM.
5XXX Selects CRTC.

FIGURE 9. Example From the New Row Start Look Up Table

ROW LOADING DETAILS

Obtaining the next starting row address for the CRT controller is accomplished by an addressing and adding scheme from the new row start look-up table. The same scheme is used to determine any needed address, given the row number.

Figure 9 shows a row number and address taken from the new row start look-up table.

The row number is loaded from the reference table in RAM to a register. The CPU determines the starting address from the row number and stores it in a 16-bit pointer register. The higher order 4 bits contain address for the RAM or the CRT controller, (Figure 8).

Here are the details of how this is accomplished. Refer to the new row start interrupt in the software listing and Figure 9.

The CPU D-E registers are loaded to point to a row number in the reference table. The number is put in the accumulator and moved into the E register. The D-E register in this example now contains 3F20 which points to NRS HIGH ROW DATA (3A). The addressed data is moved to the accumulator and then to the H register. If it was desired to point to the CRTC then 20H would have been added to it first. The D-E register still contains 3F20H. To obtain the NRS LOW ROW DATA the E register is moved to the accumulator and 30H is added to it. Now the D-E register contains 3F50H and points to NRS LOW ROW DATA (00H). The data is loaded to the accumulator and then to the L register. The H-L registers contain 3A00H which is the starting row address for row number 20H. The method just described is used throughout the terminals program to move the cursor, load the top of page, and load the new starting row address in the CRTC.

VERTICAL INTERRUPT

The vertical interrupt occurs when the CRTC has completed refreshing a video page (1920 characters) of information. Vertical blanking identifies that condition and interrupts the CPU forcing it to the vertical interrupt routine. Refer to the vertical interrupt in the flow chart. The routine moves the first row number to the CRTC row number, updating it so the next new row start load occurs with the top of the page address or the first row of the video screen.

KEYBOARD INTERRUPT

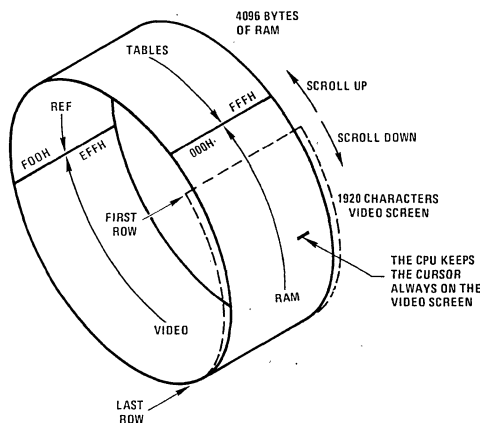
The external keyboard requirements are ASCII outputs with a suitable strobe to interrupt the CPU for keyboard servicing. Refer to the keyboard interrupt in the flow chart. After the keyboard buffer is read the data byte is tested for a (CNTL E), new baud rate command. If the test fails the CPU writes the data byte to the ACE. Passing the test forces the CPU to read the baud switch and load the ACE with the new baud rate.

ACE INTERRUPT

As mentioned above, a data byte read from the keyboard that is not a baud rate command enters the accumulator. The CPU writes the data byte from the accumulator to

the transmitter holding register in the ACE. The ACE proceeds to shift out the data byte, with the appropriate start and stop bits, serially from the (SOUT) output. The data is shifted to the serial input (SIN) of the ACE and loaded into the receiver holding register. When the register is full the ACE interrupts the CPU, initializing the ACE service routine. Refer to the ACE interrupt in the flow chart.

The CPU reads the receiver holding register in the ACE. Reading the ACE resets the interrupt. The data byte now resides in the accumulator. The CPU tests for a control or an escape function. The function is executed if test conditions are met. Refer to the keyboard interrupt routine in the software listing. The data byte is written to the video RAM at the cursor address which appears on the monitor screen. The cursor and character numbers are incremented as long as it is not at the end of a row. A character at the end of a row requires further testing to recognize the following situations. Is it the last row on the monitor's screen? Or is it on the maximum row of the video RAM? Essentially, the cursor is forced to stay visible on the video monitor's screen and video RAM is always kept out of scratch pad RAM, (Figure 10).



The video screen is allowed to scroll only through the video RAM (000H to EFFH). The CPU keeps the video screen within these bounds by loading the new row start register with that address range only (row 00H to 2FH).

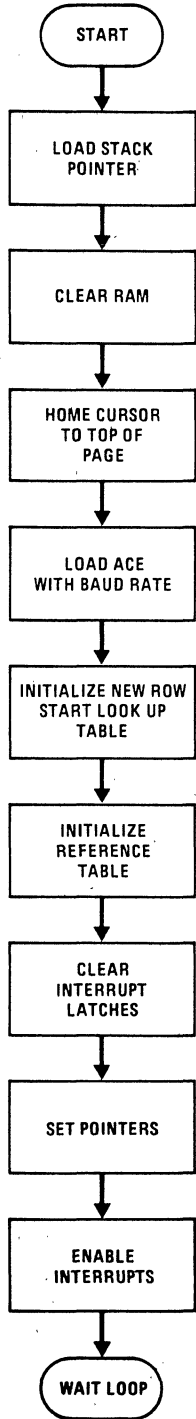
FIGURE 10. Drum Analogy for the RAM

FULL/HALF DUPLEX OPERATION

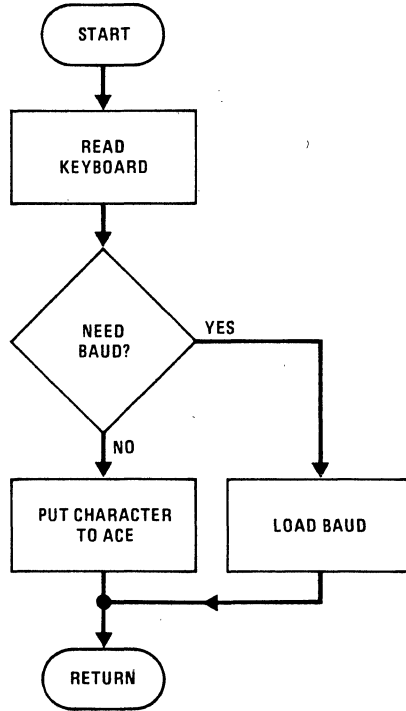
The data terminal and a host computer in the full duplex mode of operation would receive the serial information, process it, and send it back to the SIN input of ACE. Using the terminal in a stand-alone mode for testing, the serial out SOUT is tied to the serial in SIN of the ACE. In the half duplex mode a data byte is sent to the host computer at the same time it is sent to the terminal. When the data terminal is set up to communicate with a host computer the full duplex mode of operation is desirable.

DP8350/INS8080 VIDEO DATA TERMINAL BASIC SOFTWARE FLOW CHART

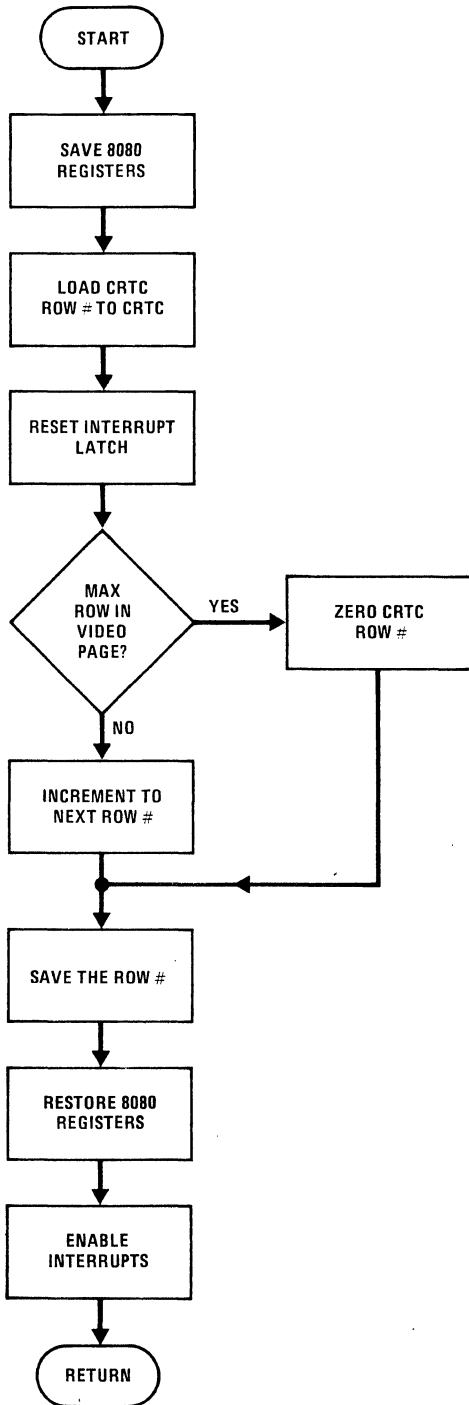
Initialization



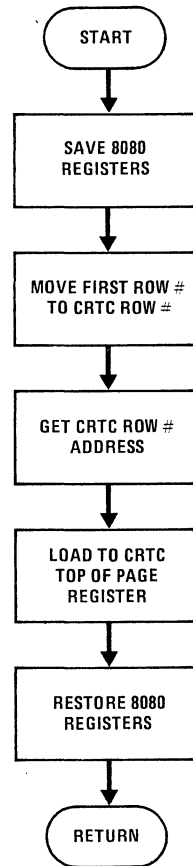
Keyboard Interrupt



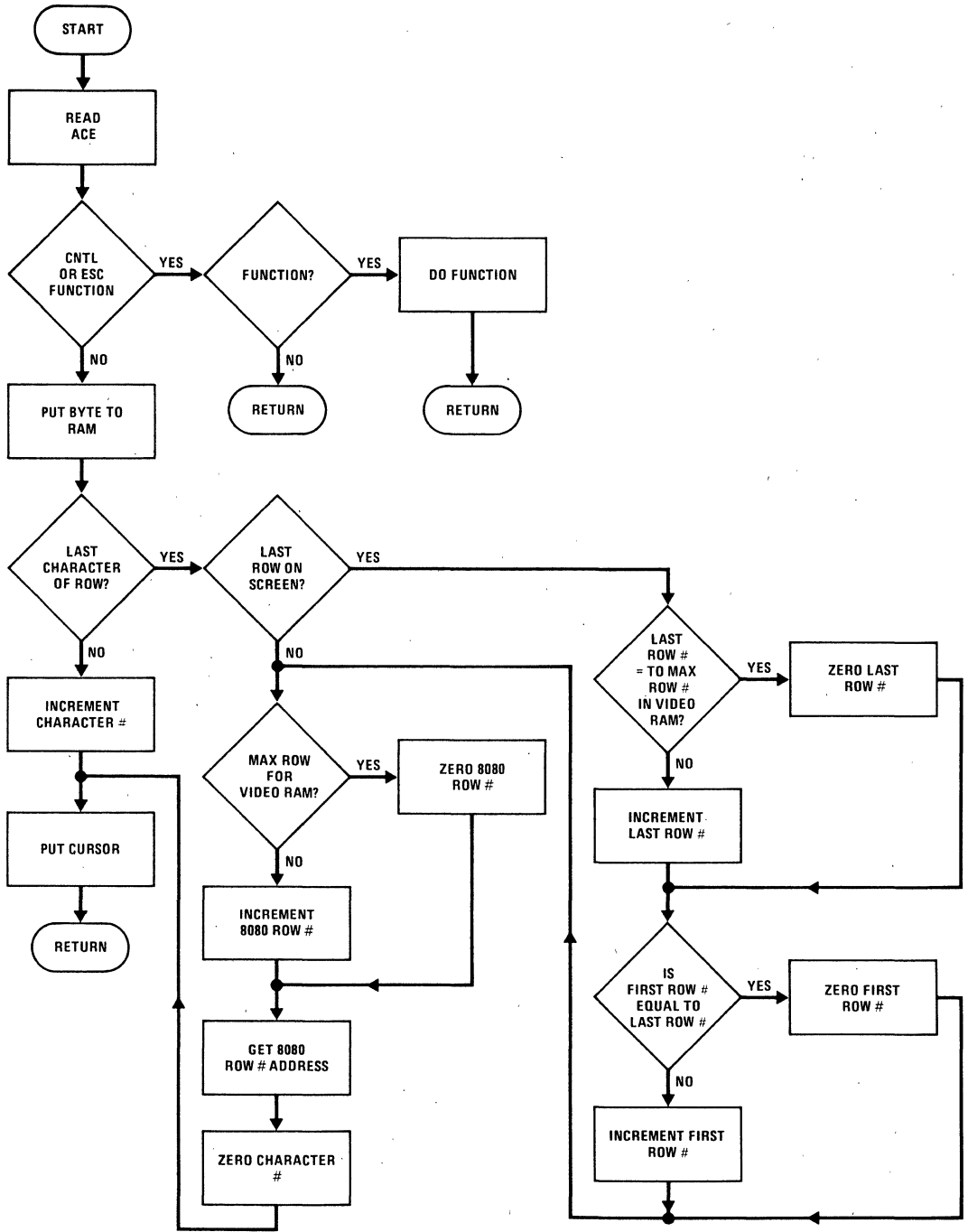
New Row Start Interrupt



Vertical Interrupt



ACE Interrupt



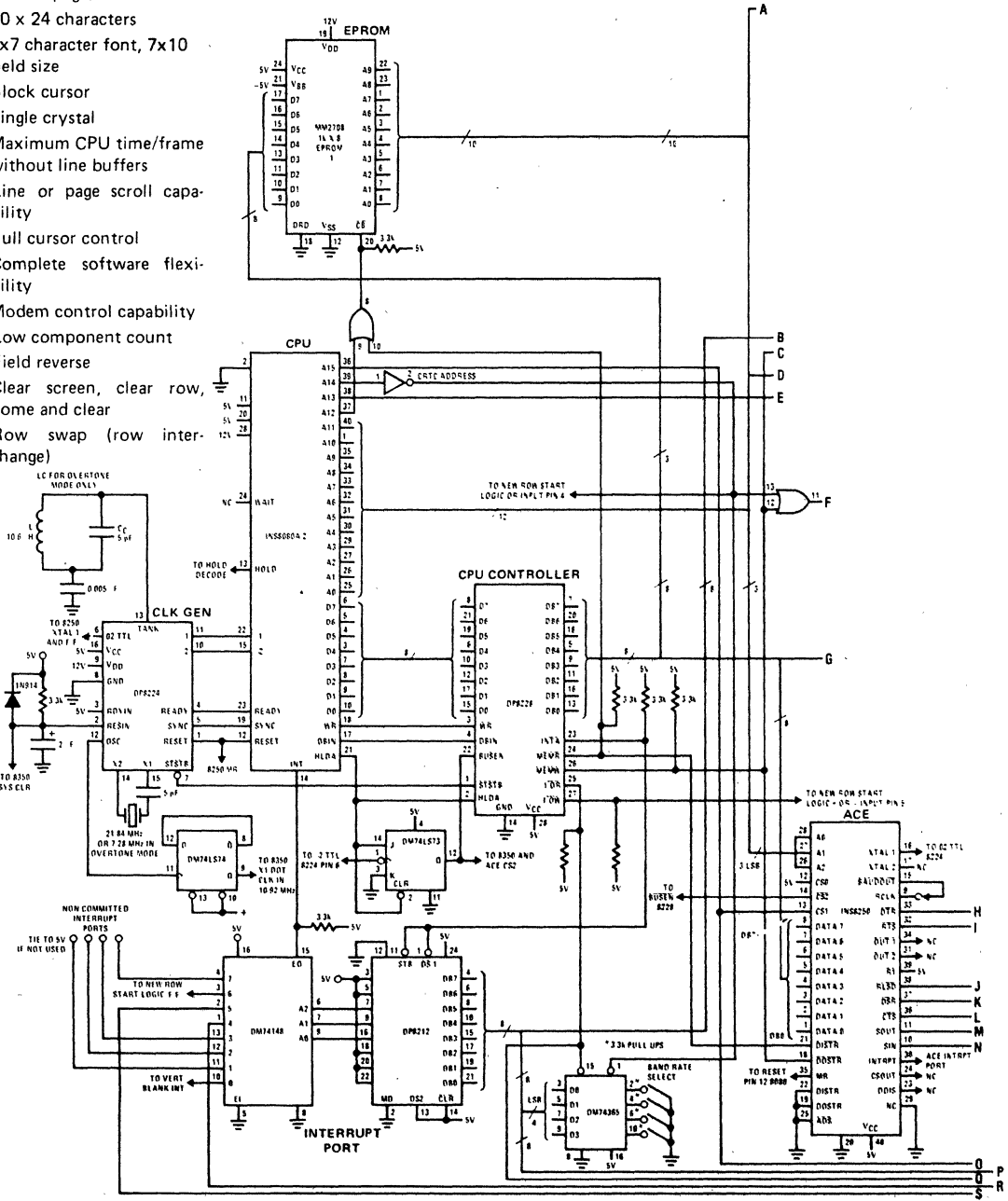
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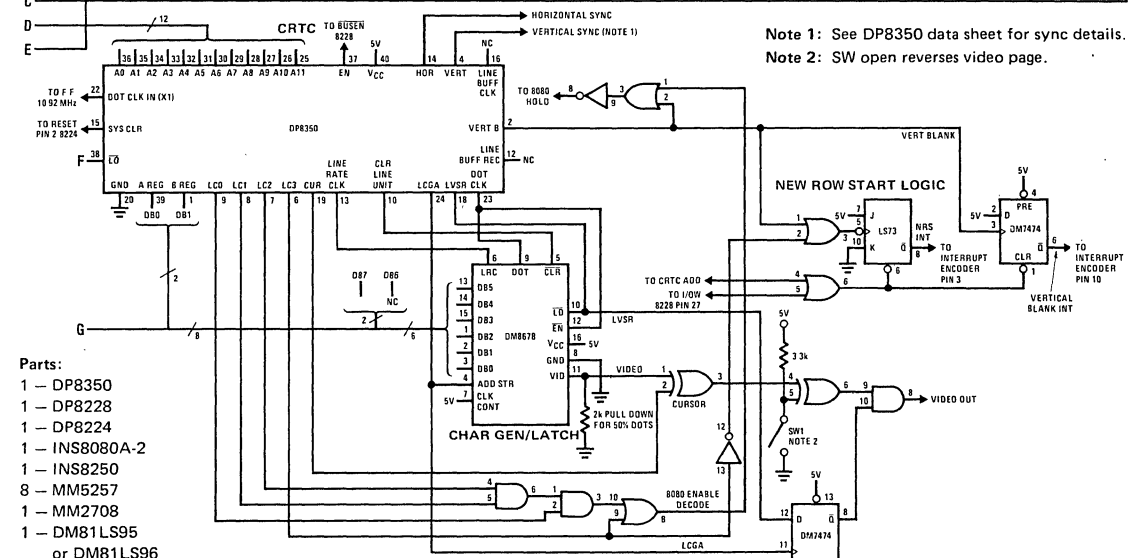
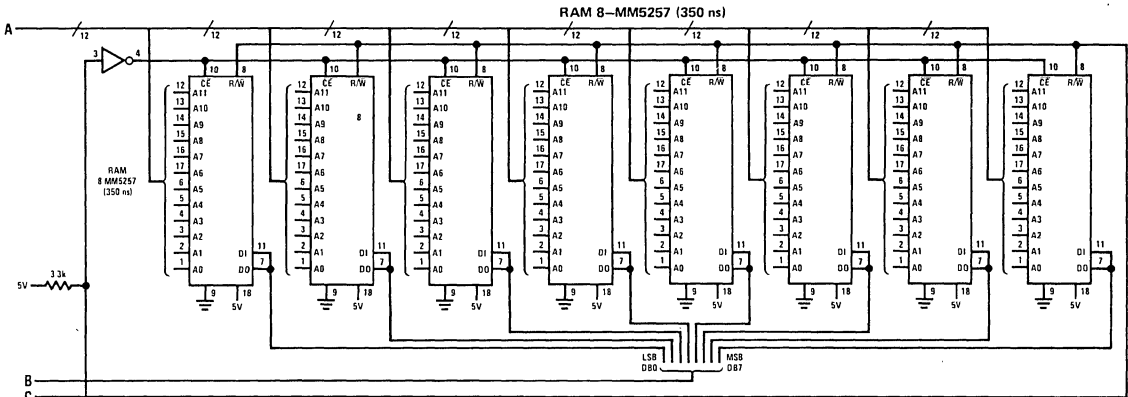
1 TITLE CRTC , 8080A 02/15/78
2
3 ** NATIONAL SEMICONDUCTOR S
4 SERIES PROGRAMMABLE CRT CONTROLLER BOARD **
5
6 .AL BRILLIOTTO-JIM TROUTNER
7
8 0060 LASTROW = 060
9 0061 ROW8080 = 061
10 0062 FIRSTROW = 062
11 0063 CHARNUM = 063
12 0064 CRTCRW = 064
13 0065 ROWSAVE = 065
14 0066 TEMP1 = 066
15 0067 TEMP2 = 067
16 0068 IMASI = 068
17
18 0000 =0000
19 0000 F3 START DI ,DISABLE INTERRUPTS
20 0001 31FF2F LXI SP,03FFF ,LOAD STACK POINTER
21 0002 C35B00 JMP INIT ,JUMP TO INITILIZE ROUTINE
22 0007 =0008
23 0008 C32502 JMP NEWRO ,NEW ROW START INTERRUPT
24 0008 =0010
25 0010 C34A01 JMP INTACE ,ACE INTERRUPT
26 0013 =0018
27 0018 C33601 JMP INTB ,KEYBOARD INTERRUPT
28 0018 =0038
29 0038 C34F02 JMP VERTI ,VERTICAL INTERRUPT
30 0020 210030 INIT LXI H,03000 ,1ST RAM ADDRESS
31 003E 0E20 MOV A,C,020 ,ASCII SPACE INTO C REG
32 0040 3E3F MVI A,03F ,MAX RAM ADDRESS
33 0042 71 CLRAM MOV M,C ,ASCII SPACE INTO MEM
34 0043 23 INX H ,NEXT RAM ADDRESS
35 0044 EC JMP H ,MAX RAM ADDRESS
36 0045 C24200 JNZ CLRAM ,IF NO THEN NEXT ADD
37 0048 0E00 MVI C,000
38 004A 2E40 MVI A,040
39 004C 71 CLRAM1 MOV M,C
40 004E 23 INX H
41 004E EC CMP H
42 004F C24C00 JNZ CLRAM1
43 0052 C08700 CALL HMCR ,GO TO CUR HOME ROUTINE
44 0055 C09300 CALL BAUD ,GO TO BAUD LOAD ROUTINE
45
46 ,NEW ROW START LOGI UP TADLE GENERATION
47
48 0058 21003F LXI H,03F00 ,N R S HIGH ADDRESS
49 0058 11303F LXI D,03F30 ,N R S LOW ADDRESS
50 005E 010030 LXI B,03000 ,N R S ADDRESS DATA
51 0061 70 NRS MOV M,D ,STORE TO N R S DATA TABLE
52 0062 79 A,C ,N R S DATA LOW TO ACC
53 0063 12 STAX D ,STORE TO N R S DATA TABLE L
54 0064 C650 ADI 050 ,ACC READY FOR NEXT LOAD
55 0066 4F MOV C,A ,ACC TO N R S DATA HIGH
56 0067 78 MVI A,E ,N R S DATA TO ACC
57 0068 CE00 ACI 000 ,ADD CARRY BIT TO DATA HIGH
58 006A 47 MOV D,A ,MOVE RESULT TO N R S DATA H
59 006B 2C INR L ,INCREMENT N R S HIGH ADD
60 006C 1C INC E ,INCREMENT N R S LOW ADD
61 006D 76 MOV A,E ,N R S ADD LOW TO ACC
62 006E FE60 CPI LASTROW ,MAX TABLE ADDRESS
63 0070 C26100 JNZ NRS ,IF FALSE JUMP
64
65 ,REFERENCE TABLE INITILIZE
66
67 0073 3E17 MVI A,017 ,LAST ROW NUMBER TO ACC
68 0075 12 STAX D ,STORE TO REFERENCE TABLE
69
70 ,CLEAR PERIPHERAL INTERRUPT FLOPS
71
72 0076 0340 OUT 040 ,N R S INTERRUPT CLEAR
73 0078 0B80 IN 080 ,KEYBOARD INTERRUPT CLEAR
74
75 ,SET UP POINTERS
76
77 007A 11603F LXI D,03F60 ,POINT D-E TO REFERENCE TABLE
78 007D 210030 LXI H,03000 ,POINT H-L TO 1ST RAM LOCATI
79 0080 010000 LXI B,09000 ,POINT B-C TO ACE
80
81 ,WAIT LOOP FOR INTERUPTS
82
83 0083 FE BACI EI ,ENABLE INTERRUPTS
84 0084 C3E800 JMP BACI ,LOOP UNTIL INTERRUPTED
85
86 ,HOME UP CURSOR
87
88 0087 210050 HMCR LXI H,05000 ,POINT B-C TO CRTC
89 008A 3E02 MVI A,002 ,T O P REGISTER SELECT
90 008C 77 MOV M,A ,T O P LOAD
91 008D 3C INR A ,CURSOR REGISTER SELECT
92 008E 77 MOV M,A ,CURSOR LOADS TO T O P
93 008F 210020 LXI H,03000 ,POINT H-L TO 1ST RAM ADD
94 0092 C9 RET ,RETURN
95
96 ,BAUD RATE SELECT
97
98 0093 05 BAUD PUSH D ,SAVE D-E REGISTERS
99 0094 0B40 IN 040 ,READ BAUD SELECT CODE
100 0096 DE00 ANI 00F ,ZERO THE HIGH ORDER 4 BITS
101 0098 FE00 CPI 000 ,110 BAUD ROUTINE
102 009A C0A400 JZ E110 ,110 BAUD ROUTINE
103 009D FE01 CPI 001 ,150 BAUD ROUTINE
104 009F C0A000 JZ B150 ,150 BAUD ROUTINE
105 00A2 FE02 CPI 002 ,300 BAUD ROUTINE
106 00A4 C0E000 JZ E200 ,300 BAUD ROUTINE
107 00A7 FE03 CPI 003 ,600 BAUD ROUTINE
108 00AA CAE600 JZ B600 ,600 BAUD ROUTINE
109 00AC FE04 CPI 004 ,1200 BAUD ROUTINE
110 00AE C0E000 JZ E1200 ,1200 BAUD ROUTINE
111 00B1 FE05 CPI 005 ,1800 BAUD ROUTINE
112 00B3 CAF200 JZ B1800 ,1800 BAUD ROUTINE
113 00B6 FE06 CPI 006 ,2400 BAUD ROUTINE
114 00B8 C0F500 JZ E2400 ,2400 BAUD ROUTINE
115 00BB FE07 CPI 007 ,2400 BAUD ROUTINE
116 00BD CAFE00 JZ B2400 ,2400 BAUD ROUTINE
117 00C0 FE08 CPI 008 ,3600 BAUD ROUTINE
118 00C2 C0A401 JZ E3600 ,3600 BAUD ROUTINE
119 00C5 FE09 CPI 009 ,4800 BAUD ROUTINE
120 00C7 C0A001 JZ B4800 ,4800 BAUD ROUTINE
121 00CA FE0A CPI 00A ,7200 BAUD ROUTINE
122 00CC C01001 JZ E7200 ,7200 BAUD ROUTINE
123 00CF FE0B CPI 00B ,9600 BAUD ROUTINE
124 00D1 C01601 JZ B9600 ,9600 BAUD ROUTINE
125
126 ,BAUD RATE SET UP ROUTINES
127
128 00DA 116305 B110 LXI D,00563 ,110 BAUD DIVISOR
129 00E7 C31E01 ACLEL JZ E110 ,GO TO ACE LOAD ROUTINE
130 00DA 11F303 B150 LXI D,005F3 ,150 BAUD DIVISOR
131 00ED C31C01 LXI D,005E0 ,110 BAUD DIVISOR
132 00E0 11F901 B300 LXI D,001F9 ,300 BAUD DIVISOR
133 00E2 C31C01 ACLEL JMP
134 00E6 11FC00 B600 LXI D,000FC ,600 BAUD DIVISOR

```

FEATURES

- Keyboard input port
- Serial I/O up to 9600 baud
4k bytes RAM
1k byte ROM
- 2 video pages
- 80 x 24 characters
- 5x7 character font, 7x10 field size
- Block cursor
- Single crystal
- Maximum CPU time/frame without line buffers
- Line or page scroll capability
- Full cursor control
- Complete software flexibility
- Modem control capability
- Low component count
- Field reverse
- Clear screen, clear row, home and clear
- Row swap (row interchange)





Note 1: See DP8350 data sheet for sync details.
 Note 2: SW open reverses video page.

- Parts:
- 1 - DP8350
 - 1 - DP8228
 - 1 - DP8224
 - 1 - INS8080A-2
 - 1 - INS8250
 - 8 - MM5257
 - 1 - MM2708
 - 1 - DM81LS95 or DM81LS96
 - 2 - DM74LS32 (V_{CC} 14, 7 GND)
 - 1 - DM74LS74 (V_{CC} 14, 7 GND)
 - 1 - DM74LS08 (V_{CC} 14, 7 GND)
 - 1 - DM74LS04 (V_{CC} 14, 7 GND)
 - 1 - DM74LS73 (V_{CC} 14, 11 GND)
 - 1 - DM74365
 - 1 - DM74148
 - 1 - DM7474
 - 1 - DP8212
 - 1 - DM74LS86
 - 1 - DM8678CAB
 - 2 - Res. arrays, 3.3k
 - 1 - 21.84 Mhz Xtal
- Bypass capacitors on all parts

Table with columns for address, instruction, register/operand, and comment. Contains assembly code for various routines like CARRAGE RETURN, ZERO ROW ZERO, and CURSOR TO THE BEGINNING OF P.

```

534 031E 3E2F R048 MVI A,02F ;CHANGE 8080 ROW #
535 0320 77 MOV M,A ;TO 23D AND STORE
536 0321 C30103 JMP LOOP1 ;JUMP TO POINTER EXCHANGE ROU
537
538 0324 3E2F FR048 MVI A,02F
539 0326 77 MOV M,A
540 0327 C30F03 JMP LOOP2
541
542 032A 3E2F LR048 MVI A,02F ;PUT THE 1ST ROW TO
543 032C 77 MOV M,A ;17H
544 032D C31803 JMP LOOP3 ;JUMP TO 8080 ROW # STORE
545
546 ;CLEAR ROW ROUTINE
547
548 0330 CD3603 CLR0W CALL CLR0W1
549 0333 C36E02 JMP CR
550
551 0336 1E61 CLR0W1 MVI E,ROW8080
552 0338 CD1202 CALL LDHL
553 033B 3E50 CLR0W2 MVI A,050 ;INITLIZE LOOP COUNTER.
554 033D 3620 LOOP4 MVI M,020 ;STORE ASCII SPACE IN MEM
555 033F 3D DCR A ;DECREMENT LOOP COUNTER
556 0340 C3 RZ ;RETURN IF ZERO BIT IS SET
557 0341 23 INX H ;NEXT LOCATION
558 0342 C33D03 JMP LOOP4 ;CLEAR NEXT LOCATION.
559
560 0345 D301 BELL OUT 001 ;RING BELL
561 0347 C9 RET
562
563 0348 AF IVERTN XRA A
564 0349 1E68 MVI E,IMASK ;POINT D.E TO MASK
565 034B 1A LDA D
566 034C 17 RAL ;CK BIT 8 STATUS
567 034D D85203 JC RESET ;INVERT BIT 8
568 0350 3E80 MVI A,080 ;STORE OUT NEM MASK
569 0352 12 RESET STAX D
570 0353 C9 RET
571
572 0354 E5 IVERTR PUSH H
573 0355 1E61 MVI E,ROW8080
574 0357 C8E202 CALL LDHL ;LOAD 1ST ADD OF 8080ROW TO
575 035A 1E50 MVI E,050 ;SET COUNTER
576 035C 7E LOOP6 MOV A,M ;GET CHAR
577 035D 17 RAL ;CK BIT 8 STATUS AND INVERT
578 035E DA7003 JC RESET1
579 0361 1F RAR
580 0362 F680 ORI 080 ;MASK BIT 8 HIGH
581 0364 77 BACK2 MOV M,A ;STORE MOD CHAR TO MEM
582 0365 23 INX H ;POINT TO NEXT MEM
583 0366 78 MOV A,E
584 0367 FE01 CPI 001
585 0369 CA7603 JZ DONE ;RETURN IF COUNT = ZERO
586 036C 1D DCR E ;DEC COUNTER
587 036D C35C03 JMP LOOP6
588
589 0370 1F RESET1 RAR
590 0371 E67F ANI 07F ;RESET BIT 8
591 0373 C36403 JMP BACK2
592
593 0376 E1 DONE POP H
594 0377 C9 RET
595 0000 END START

```

DEFINITIONS

ACE – Asynchronous communication element

CRTC – Cathode ray tube controller

Video Page – Visible screen data

Video RAM – Entire portion of RAM used only for display

First Row # – Address for top row of video page

Last Row # – Address for bottom row of video page

CRTC Row # – Address for next row load

8080 Row # – Address for cursor row

Character # – Character location in a row

XXXXH are hexadecimal numbers

REFERENCES

National Semiconductor Data Sheets:

DP8350 Series Programmable CRT Controllers
INS8250 Asynchronous Communications Element
DM8678 Bipolar Character Generator
INS8080 Assembly and Reference Manuals

National Semiconductor Application Notes:

Simplify CRT Terminal Design with the DP8350,
AN-198

DM8678 Bipolar Character Generator, AN-167

Data Bus and Differential Line Drivers and Receivers,
AN-83

Transmission Line Characteristics, AN-108

Hardware Reference Manual BLC 80/10 Board Level
Computer. National Semiconductor Microcomputer
Systems Chapter 6 – System Interfacing.

Graphics Using the DP8350 Series of CRT Controllers

National Semiconductor
Application Note 212
Charles Carinalli
December 1978



The DP8350 CRT Controller series is a versatile building block for both low and high-end CRT terminal applications. This application note demonstrates how the DP8350 may be used in CRT graphics applications. Although this presentation is general, when specific examples are given the DP8350 ROM programmed version of the DP8350 series will be used (80 characters per row, 24 character rows, 5 x 7 character, 7 x 10 character field size).

BACKGROUND INFORMATION

The basic function of the DP8350 CRT controller is to control the elements of the "video loop" (Figure 1). A memory address generated by the CRT controller is presented to the CRT memory, which stores a record of what appears on the CRT display. The character generator converts this stored information into serial video data to the CRT monitor. The intensity of the CRT electron beam is modulated by this video data and its position is controlled by the horizontal and vertical sync pulses generated by the CRT controller.

The CRT screen video area is divided into character cells (Figure 2). Each cell has a unique CRT memory address. The DP8350 must present the correct character cell address to the CRT memory at the appropriate CRT beam location. Use of the line counter outputs of the DP8350 make possible the subdivision of each character cell address into the unique scan line of the present CRT beam location.

For the DP8350 and its unique internal ROM program format, each character cell is composed of 70 dots (7 dots wide and 10 dots high) Figure 3. When using the DP8350, each of these dots may be active video data. Typically however, in alphanumeric display systems, the character generator will provide cell to cell character spacing on the CRT screen by blanking some number of rows and columns of dots. That is why the DP8350's 7 x 10 dot field is used with a 5 x 7 character generator (2 horizontal and 3 vertical dot spaces).

In fact, it is the character generator that restricts the use of the full character cell dot field, not the DP8350! Using a character generator which allows video on every scan line and all dots of the cell width, makes graphic capability possible. This type of graphic display generation is called "character generator graphics."

All of the dots on the CRT display may also be independently controlled by a separate CRT memory address location; this is called "memory mapped graphics."

Both of these graphics display generation techniques will be discussed here, with demonstrations of how the DP8350 series may be used to reduce total component count.

CHARACTER GENERATOR GRAPHICS

In this graphics system (Figure 4) the character generator block contains a ROM that has been programmed with graphic symbols whose size is contained within the character cell size. This ROM may at the same time contain alphanumeric characters that do not use the full character cell size.

The block representation and operation of this system is the same as the alphanumeric's system previously described. The CRT memory presents the same character cell data to the character generator on every scan line of that character cell address. The character generator ROM is organized with addresses defining a particular symbol and addresses defining which scan line of a character row the CRT electron beam is currently on; thus defining the video data for that scan line of the symbol. The scan line address data comes directly from the DP8350. The parallel data that results is video data for that screen address cell width. This data is then serially shifted to the CRT monitor with a parallel to serial shift register.

This system allows every scan line of a character row to have active video information; thus the graphics symbol may be programmed to all sides of the character cell providing continuity from cell to cell both horizontally and vertically. At the same time, the alphanumeric's character may be programmed with cell to cell spacing.

Character generator graphics is the simplest most cost-effective approach to CRT graphics. It requires a minimum of software development and hardware support. The DP8350 CRT controller provides all the required timing and control pulses for the CRT memory, character generator, and CRT monitor.

Graphics capability with this system, however, is somewhat limited since individual dot control is not possible; only character cell symbol control is available. This system does apply well in such applications as bar graphs, circuit schematics, or flow charts and when these need to be combined with alphanumeric data.

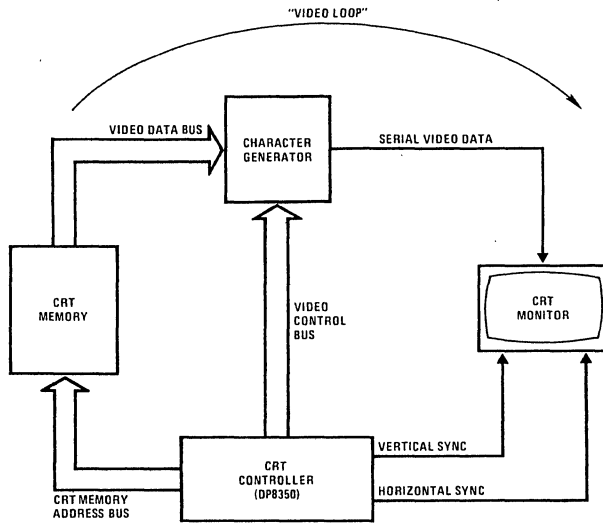


FIGURE 1. Elements of the "Video Loop"

CHARACTER CELLS PER ROW

C H A R A C T E R	0	1	2	3	4	...	75	76	77	78	79	ROW 1
	80	81	82	83	84	...	155	156	157	158	159	ROW 2
	160	161	162	163	164	...	235	236	237	238	239	ROW 3
	240	241	242	243	244	...	315	316	317	318	319	ROW 4
C E L L	ROW 22
	ROW 23
	ROW 24
	ROW 24
R O W S	1680	1681	1682	1683	1684	...	1755	1756	1757	1758	1759	ROW 22
	1760	1761	1762	1763	1764	...	1835	1836	1837	1838	1839	ROW 23
	1840	1841	1842	1843	1844	...	1915	1916	1917	1918	1919	ROW 24

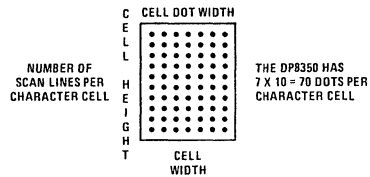


FIGURE 3. The DP8350 Character Cell is 7 Dots Wide and 10 Dots High

FIGURE 2. CRT Screen Cell Address Map Presented to CRT Memory by the DP8350 (Top of Page Register Contains Address 0) Character Cells Per Row = 80 Character Rows Per Frame = 24

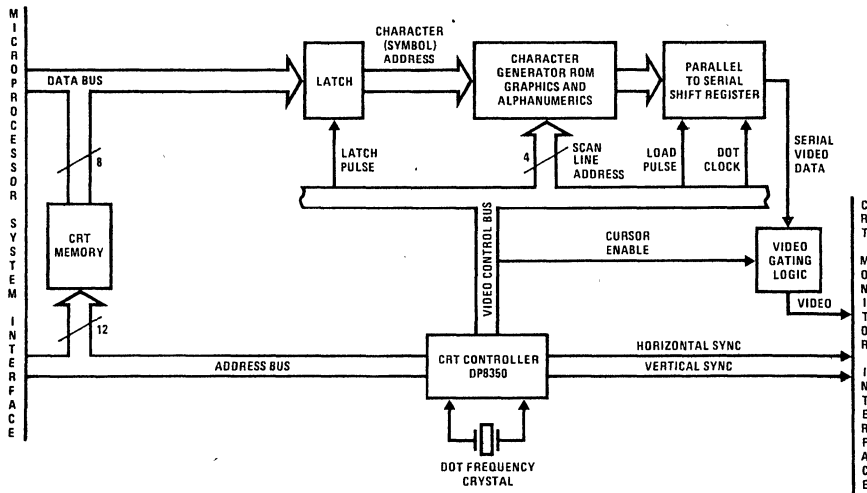


FIGURE 4. Character Generator Graphics

CHARACTER GENERATOR GRAPHICS—WITH LINE BUFFERS

Modification of the character generator graphics block diagram is possible with the addition of a recirculating line buffer placed between the CRT memory and the character generator (Figure 5). In this case the character generator addresses for a character row are loaded serially into this shift register on the scan line before the first video scan line of a character row. These addresses are then recirculated for the number of scan lines per character row minus one (then the next character row of addresses is loaded). This system allows access to the CRT memory by the system controller on all but one scan line of a video character row. In contrast, the system previously described would have allowed access only during blanking intervals. In systems that require heavy access to the CRT memory to update screen information, this approach is very attractive.

In this case, as before, all the required control pulses for the "video loop" are provided by the DP8350 CRT controller.

MEMORY MAPPED GRAPHICS

If a very high resolution graphics display is required, every dot of the CRT display may be independently controlled. In this case, every dot of the CRT screen may be mapped to a specific CRT memory data bit—thus the name Memory Mapped Graphics. This type of system is obviously a more costly type of graphics, since to control every dot not only is there a need for more CRT memory, but the microprocessor overhead in such

a system will be greater—both software and hardware. In any case, the DP8350 easily adapts to such a system as demonstrated in Figure 6.

In this approach, if you subdivide each character cell such that each scan line of the cell may be independently addressed, then from the CRT memory block instead of 8 bits of data defining a character cell code to the character generator, you get 8 bits of direct video data. Then the CRT memory block serves double duty—CRT memory storage and symbol or character generator. All that is left to do is convert this parallel video data to serial video data as before.

In the case of the DP8350 internal ROM format program, each cell is 7 dots wide; thus only 7 bits of video data are needed per character cell/scan line address. The DP8350 addresses the memory block as before with the character cell address, but in this case also with the scan line address. In this manner, the DP8350 series has a maximum address capability of 16 bits (64k).

VARIATIONS

If memory mapped graphics is desirable but standard alphanumeric is also required, combination of these techniques is possible. For example, if only a small portion of the CRT screen need be memory mapped and the remainder can be character generator alphanumeric and/or graphic symbols. In this case a higher order data bit from CRT memory defines whether the lower order data bits are graphics video data or ASCII and graphics symbol code. Figure 7 is a block diagram of such a system.

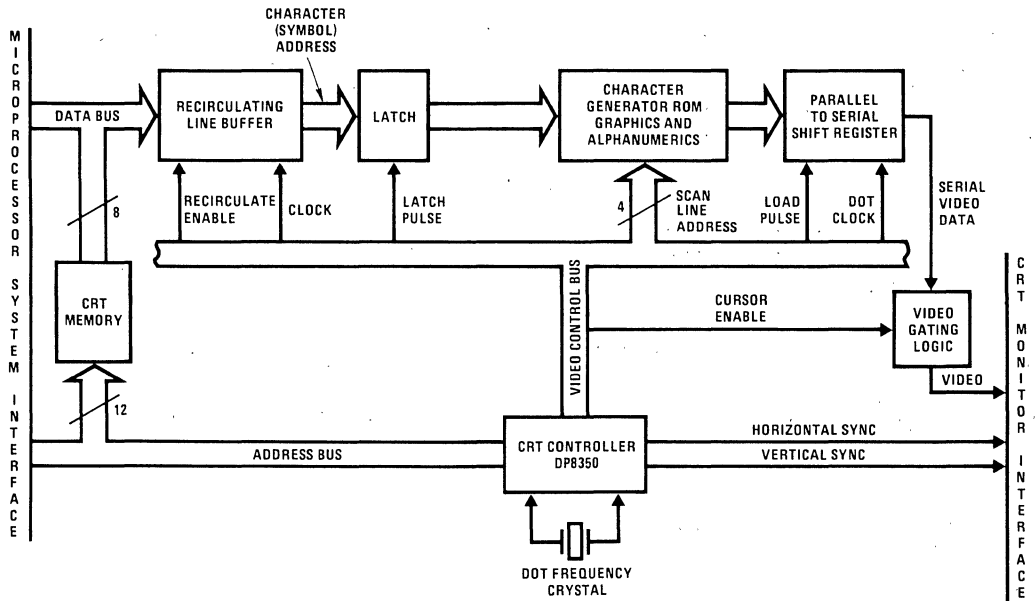


FIGURE 5. Character Generator Graphics (With Line Buffer)

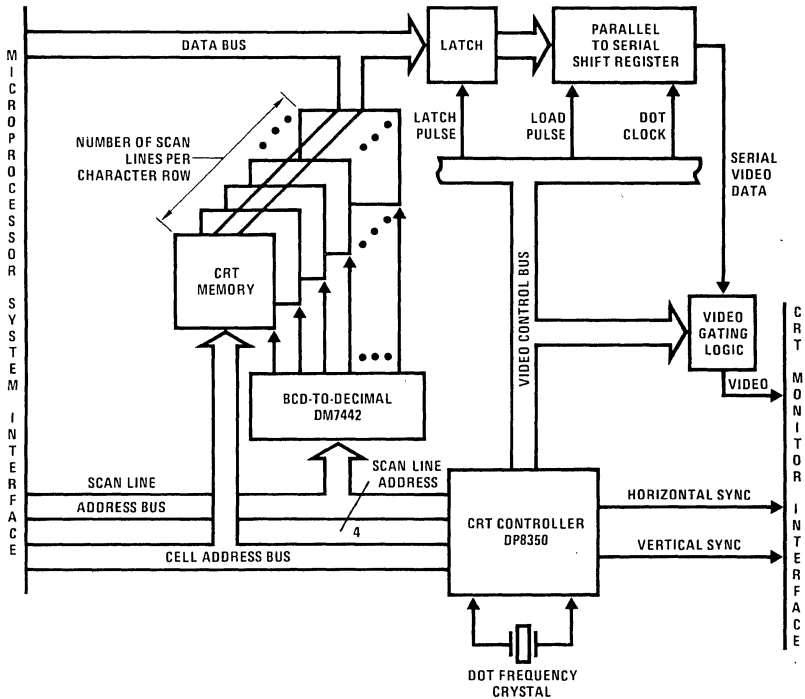


FIGURE 6. Dot by Dot (Memory Mapped) Graphics

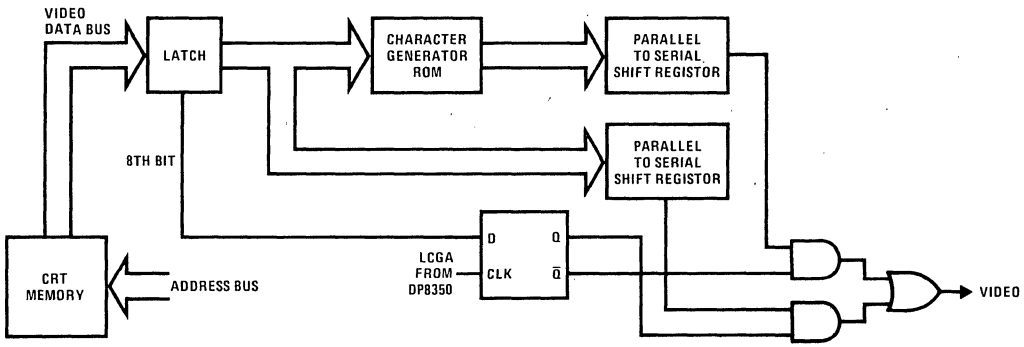


FIGURE 7. Combined Character Generator and Memory Mapped Graphics.

SUMMARY

This application note has demonstrated 2 basic graphics techniques that may be implemented using the DP8350 CRT controller. Variations to these techniques are possible such as changing character cell sizes and subdividing the character cell into dot blocks. In most cases, these variations are done to decrease hardware or software overhead. Since the DP8350 series of CRT controllers offer display format flexibility through internal ROM program variations—the device adapts equally well

to these graphics variations as it does to the standard applications.

The fact that all the required control functions for the “video loop” are contained within the same chip—the DP8350—makes it very effective in these types of applications; as a result it will produce the minimum chip count and cost.

Graphics/ Alphanumeric Systems Using the DP8350

National Semiconductor
Application Note 243
Mike Evans
April 1980



This application note summarizes some CRT terminal circuits, each with an increasing degree of graphics capability, and then goes into detail to describe a system having full graphics capability, with all dots individually programmable. All these applications use the DP8350 CRT Controller.

Here are some of the features of the full graphics system.

Hardware Features

- The hardware is designed for a 24 row by 80 column display, with 7 dots per column and 10 lines per row
- All ICs are made by National Semiconductor
- Low I.C. cost, all parts readily available
- Fits on one standard BLC80 (SBC80) card
- System performance only limited by software
- 8080 Mnemonics — useable with STARPLEX or Inteltec Development Systems
- All graphics programs very fast
Example: One dot takes 500 μ s maximum to plot
- During display time, each 7-dot cycle may be shared by the microprocessor
- 8 bit word comprises MSB as attribute and next 7 bits as 7 dot word of a character line
- Can input display data serially or parallel
- Can output display data serially or parallel
- Baud rate programmable from 110 to 56k baud
- Can be used as slave to main system
- Can copy characters from alphanumeric ROM or symbol EPROM
- 13k bytes of RAM available for user software or back-up display storage
- Analog inputs — joystick or waveforms
- Easily expandable to color graphics

Software Features

- The software is programmed for any display configuration of rows, columns, dots per column and lines per row. The hardware is designed for a 24 row by 80 column display, with 7 dots per column and 10 lines per row.
- Can perform most dumb terminal functions, including scrolling
- Simultaneous display of alphanumeric and graphics
- Identical terminals can display same information with inputs from either
- Can save displays in computer storage
- Can load displays from computer storage
- Can erase any part of display or all of it
- Can draw a rectangle linking any 2 horizontal and 2 vertical coordinates
- Can transfer in 1/10th second max any area of display to any other area or to/from back-up display storage
- Smooth movement of subject in any direction
- Immediate display of fixed diagrams
- In-system emulation of programs available

The DP8350 CRT Controller provides incrementing video addresses starting from the Top of Page address, or from a new Row Start address. These addresses and the Cursor address are loaded into their respective registers from the address bus. All video control signals are provided by the 8350, so that apart from the crystal oscillator, no extra video circuitry is required.

The DP8350 has so far been considered to be useable only in dumb terminals, whereas in fact it is easy to adapt it to more complex terminals with full graphics capability. Following is a summary of the functions of the various combinations of alphanumeric/graphics displays beginning with a dumb terminal using a monitor with 24 x 80 characters.

Dumb Terminal

The basic dumb terminal design is shown in Figure 1. Usually the microprocessor loads the Character Position RAM (or Refresh RAM) only during horizontal or vertical blanking, or during the last 3 lines of a row. The CRTC then sequentially addresses this RAM during display time. The ASCII data from this RAM (for the character selected) is outputted to the ROM of the Character Generator. The 7-dot word of this character for the line being displayed is then loaded into a shift register, and shifted out as video during the next 7-dot cycle. The ROM, line counter and shift register can be one IC, such as the DM8678 DAB Character Generator, which contains all ASCII upper case characters.

The logical choice of CRT Controller for this simple CRT terminal is the DP8350, which mates perfectly with the DM8678. The most common application is for a 24 row by 80 column display with the character field comprising of 10 lines each of 7 dots. The character itself occupies 7 lines each of 5 dots, leaving 3 lines for vertical character spacing, and 2 dots for horizontal character spacing.

Refer to AN198 and AN199 for further information on alphanumeric applications of CRTs.

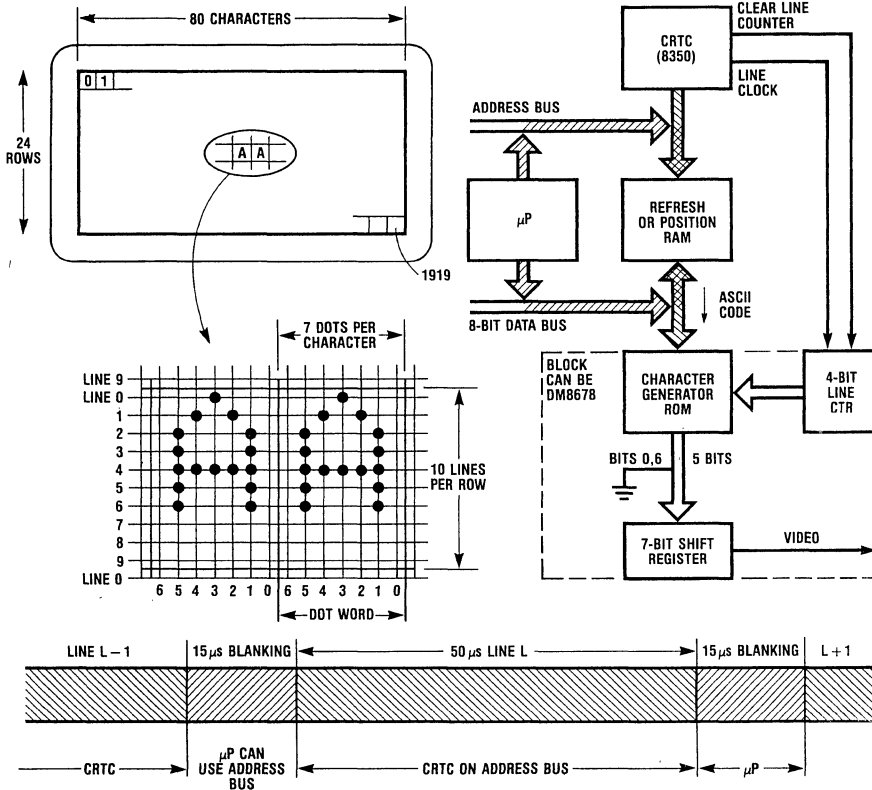


Figure 1. Simplest CRT Terminal

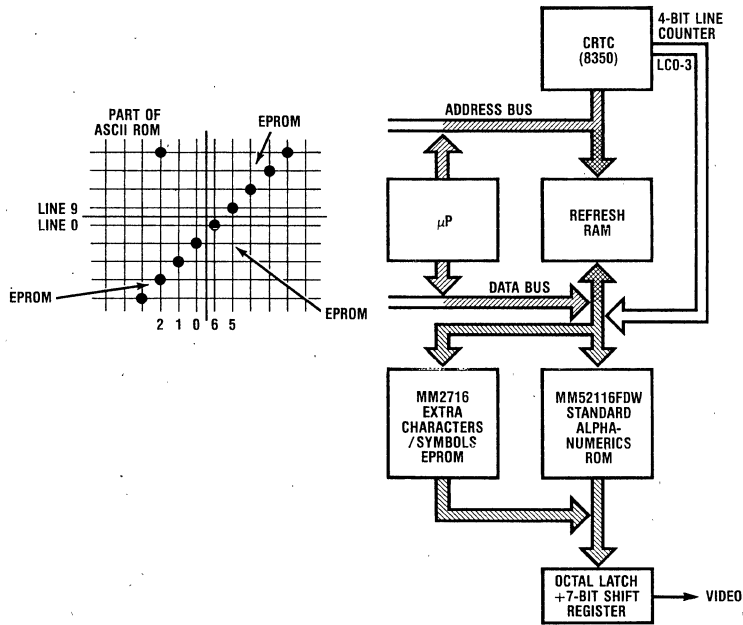
Disadvantages for Graphics

- Only characters in the Character Generator ROM can be selected
- Characters not continuous to adjacent fields
- Microprocessor thru-put 30% of maximum — not desirable for graphics

Alphanumeric Characters with Extra Symbols

When characters or symbols are required that are different from those in the ROM, then an extra EPROM such as the MM2716 can be added as shown in Figure 2. The standard characters can be selected from a separate ROM such as the MM52116FDW which contains all 128 standard ASCII characters. The EPROM is pre-programmed with additional characters or symbols. The 8350 outputs sequential addresses to the Refresh RAM, and each address is two dot cycles ahead of the shifting dot word.

The data out from the RAM must be valid 150ns after each address change. The MSB of the data selects ROM or EPROM, and the remaining 7 bits select the character. The line of the character is decoded from the 4-bit line counter outputs coming from the 8350. The ROM/EPROM now has 640-150ns (>450ns) to output the valid dot word. This has to be latched into an octal latch and held for one dot cycle before it can be loaded into the 7-bit shift register. The dots are then shifted out in the dot cycle.



Refresh RAM MSB:

- 0 selects alphanumeric ROM
- 1 selects symbol EPROM

Figure 2. Fixed Character ROM + Symbol EPROM

Disadvantages For Graphics

- Fixed graphics possible with continuous display, but limited to 128 different characters, and 128 standard alphanumerics, for all 1920 positions.
- Also it is not possible to change characters/symbols once the EPROM has been programmed.
- The Microprocessor is still slow thru-put.

Limited Graphics Terminal

To be able to generate *any* graphics symbol, a character RAM must replace the fixed ROM characters. Characters or symbols can be loaded into the RAM as required from a ROM or a pre-programmed EPROM like the MM2716 (refer to Figure 3). But now, new graphics characters can be written into the RAM from the Microprocessor. These can either be derived internally from the μ P or obtained directly from peripherals (such as serially to an Asynchronous Communications Element like the INS8250, or parallel from an external I/O port).

This limited graphics application thus requires two RAMs, the Refresh RAM (or Character Position RAM), and the Character RAM. The Refresh RAM outputs the selected character address, and the 8350 line counter outputs select the line in the Character RAM. The 7 dots outputted from this RAM are latched into the Octal Latch and held for one dot cycle. The 8th bit of data can be used as an attribute control bit. The 7 LSBs are then loaded into the 7-bit shift register.

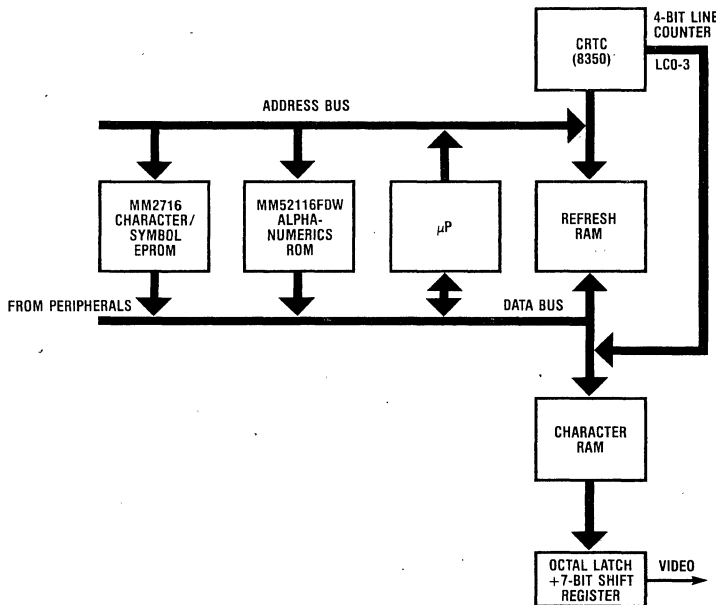


Figure 3. Character RAM with ROM/EPROM Look-Up

Disadvantage for Graphics

- Only 256 possible characters per display, with the 8-bit data bus, but can re-load different characters for a new frame.

Advantages

- Can now load standard characters or symbols from EPROM, either at switch-on or during normal running.
- Can also load characters/symbols/graphics from the μ P or peripherals, e.g., to create graphics drawings to connect to adjacent positions.
- Can now be a very fast system — by isolating the μ P address bus from the CRTC address bus, the μ P can share the dot cycle with CRTC.
- Refresh RAM and character RAM can be made the same IC by using one $8k \times 8$ quasistatic RAM.

With the new $8k \times 8$ quasistatic RAMs such as the NMC4864, the first quarter can be used as a Refresh RAM for the 1920 character positions. The RAM data outputs containing the character address can then be latched into an octal tri-state latch. If the 8350 address bus is then disabled, the octal tri-state latch can feed back to the RAM second half address inputs, along with the enabled 8350 line counter outputs. The data out from the RAM now contains the next 7-dot word to be displayed and this is then loaded into the shift register. This takes the last two thirds of the dot cycle, the first third is for the μP . With the fast cycle time of the quasistatic RAMs this 3 part cycle can easily be accomplished in one 7-dot cycle. (Refer to Figure 4.)

With the method just described it is only possible to display 256 different characters for any one page, because each character consists of 10 lines, almost filling the second half of the quasistatic RAM. If this is acceptable, then a limited graphics terminal can be easily implemented using a microprocessor, with one MM2716 instruction set EPROM, one MM52116FDW character ROM, one MM2716 symbol EPROM, one DP8350 CRT Controller, the NMC4864 quasistatic RAM, and a DM74166 shift register. The logic and drive circuitry required to control the sequencing comprises a further 15 SSI ICs. This application has not yet been built, awaiting availability of the quasistatic RAMs.

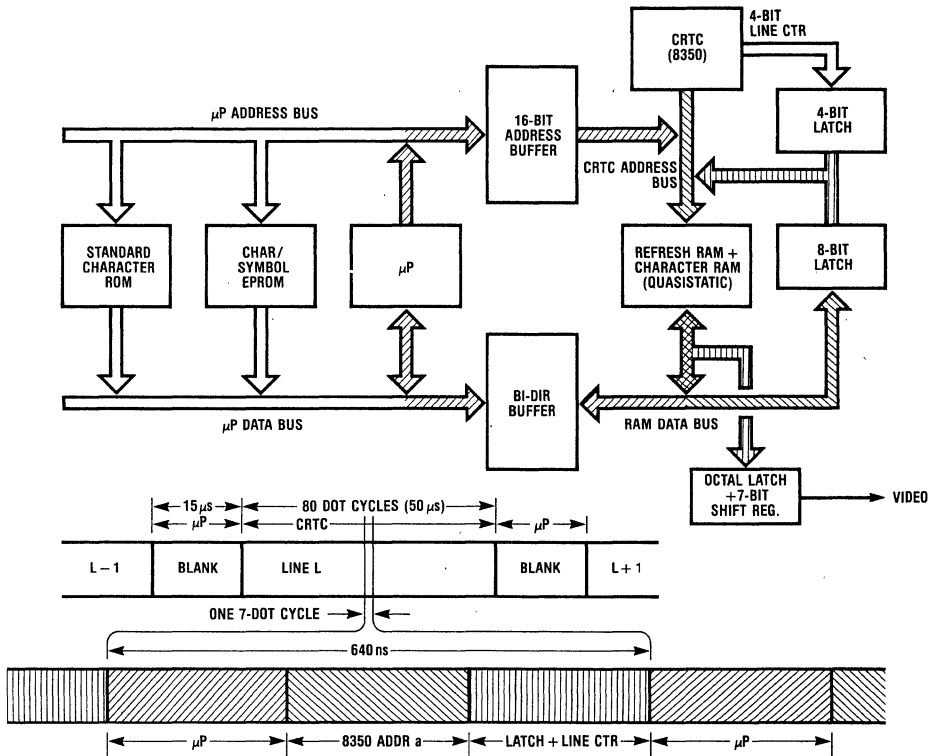


Figure 4. Limited Graphics Using a Buffered CRTC Address Bus and a Quasistatic RAM

Advantages

- Only one IC, an $8k \times 8$ quasistatic RAM, used for both the refresh RAM and character RAM
- Fast, although μP may be in the wait state for a maximum of 600ns. This is no problem because the fastest μP instruction cycle is $1\mu s$, so there will be no effect on maximum thru-put.

Disadvantages

- No quasistatics available at the time of writing
- Full graphics capability not possible

Full Graphics Capability

We need to be able to select any dot on the display, for full graphics capability, while still using the CRT controller to sequence every line of every row, as it does in the simple terminal (See Figure 5).

With the standard 24x80 character display, full graphics can be achieved by using a 24 (rows) by 80 (columns) by 10 (lines) address RAM, and selecting the 7 dots as the data word for the character position on the display and the line of that character position.

This means that alphanumeric characters can be displayed in exactly the same format as with a simple terminal, by copying the character from ROM or EPROM into the selected 10 line by 7-dot field, line by line.

Full graphics capability is also easily implemented once the relevant software algorithms have been determined.

So for full graphics, every dot is one bit of memory. There is no refresh RAM, refer to Figure 6. The CRTC scans through the Display RAM, a line at a time for each row on the CRT, causing the RAM outputs to be read every 7 dot cycle. The RAM output is shifted out two dot cycles later. The microprocessor may write into the Display RAM each 7-dot word, with "1's" representing dots.

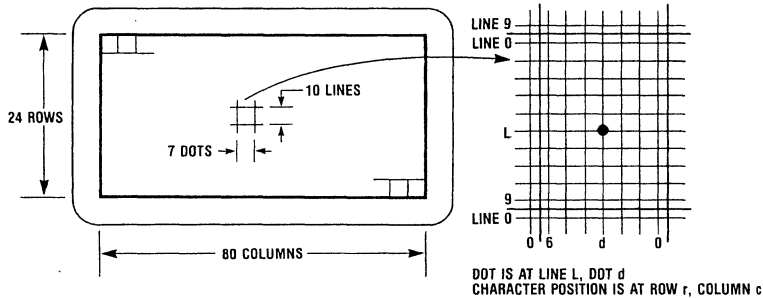


Figure 5. Full Graphics Capability Requires Individual Dot Selection

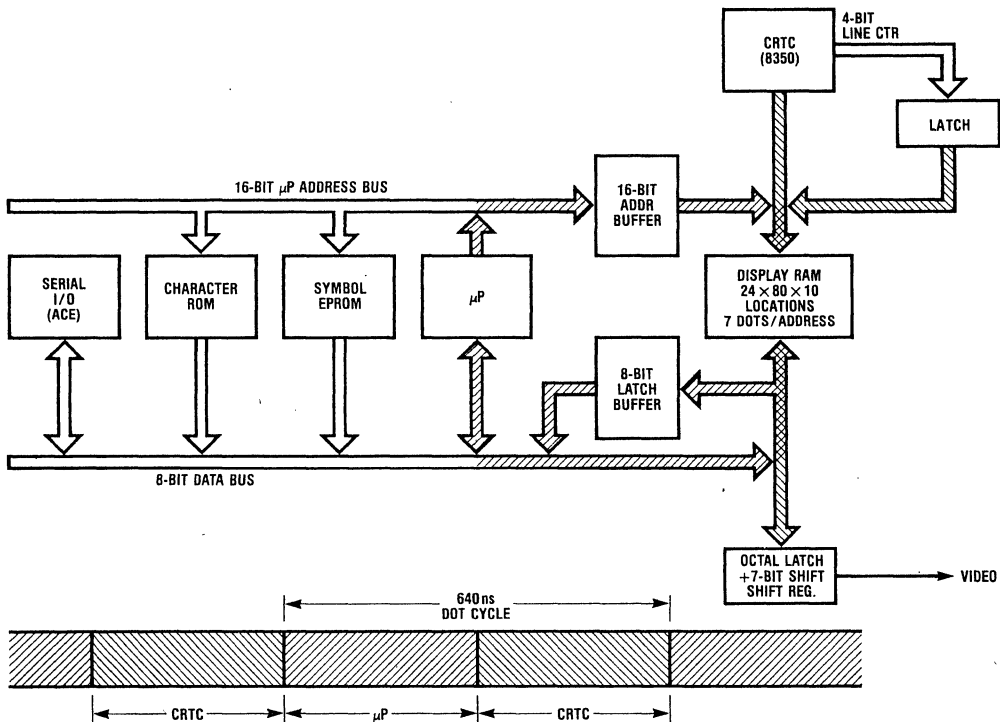


Figure 6. Full Graphics System

CRTC Address Bus Configuration

The particular RAM address to be written into is determined by its 10 × 7 character field position and the selected line of that field; refer to Figure 7.

The 11 least significant addresses A₀ to A₁₀ contain character position information from position 0 to 1919,

and the next 4 addresses A₁₁ to A₁₄ are the 8350 line counter outputs via a tri-state buffer. The most significant bit, A₁₅ is used to select the RAM when HI, and the EPROMs and peripherals when LO

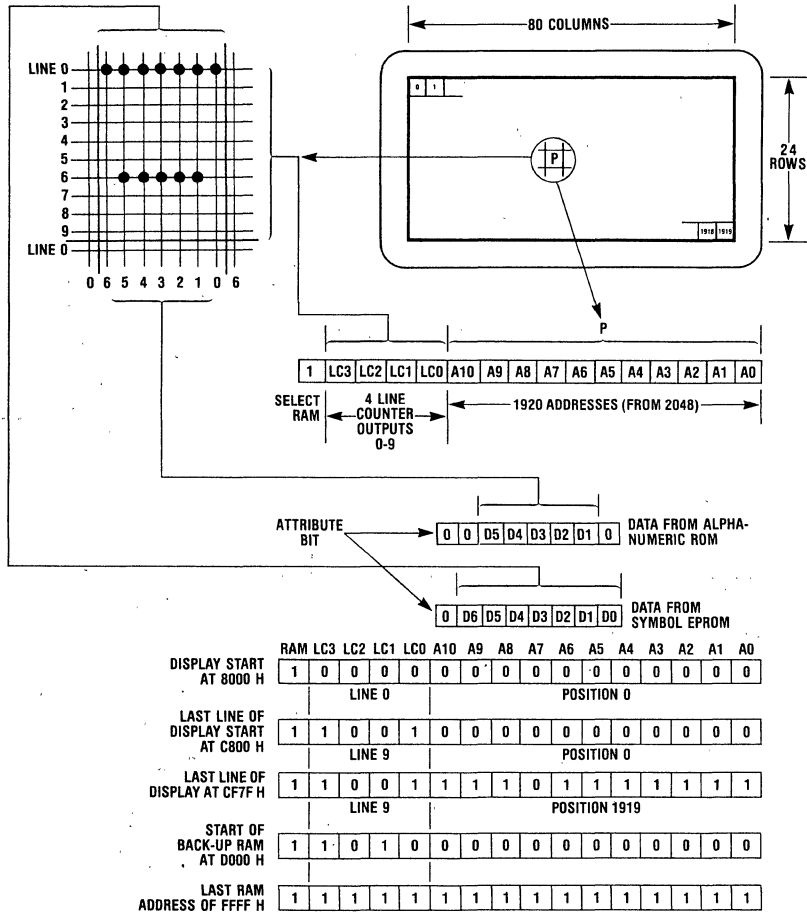


Figure 7. RAM Addressing

Graphics Design Criteria

In the simple CRT applications, the microprocessor is used mainly to re-write the Refresh RAM as new information is fed in, either from the keyboard, or from the main computer (via ACE). The μ P can still be used in this application for alphanumerics/graphics, but it is also desirable if it can perform graphics computations, such as drawing lines from the inputted coordinates.

This requires the microprocessor to be able to write 7 dot words quickly to the Display RAM. The best way to implement this is to time multiplex the dot cycle with the CRTC so that whenever the μ P requires access to the Display RAM, it merely waits for its slot in the next dot cycle, which could be up to 640 ns later. The information is either written or read after 360 ns, that is a maximum of 1 μ s after the memory access request, which is fast enough. Now the μ P no longer has to wait for blanking to be able to operate, it continues its normal operation and only enters the WAIT state during RAM access. Although this is for up to 1 μ s, in fact it is in general invisible because the μ P memory access takes at least 700 ns.

The Microprocessor

The 8080A-2 was chosen for the following reasons:

- FAST — takes 21.84 MHz (2×8350 frequency) divided by 9 (in the 8224), to give a clock cycle of 2.427 MHz, i.e., 0.41 μ s per microcycle, or 1.6 μ s for a short instruction
- Software can be developed on STARPLEX™ or Inteltec Development Systems
- INS8080A-2, DP8224 and DP8238 are low cost and available from National
- Associated circuitry previously designed in Application Note AN199

Note the DP8238 has advanced MEMW mode — desirable so that the microprocessor can go into the WAIT state earlier in the write cycle.

Interrupts

The INS8259 is ideal as an Interrupt Controller, because most interrupt signals in the system are positive going, saving D-type flip-flops. It can also be used to mask off interrupts when necessary.

Interrupt Priority

- 1) *Horizontal Sync* from the 8350, highest priority if row start has to be quickly changed, normally masked off

- 2) *Paralleled 8-Bit I/O Port*, highest priority if CRTC card is part of a master system, otherwise masked off
- 3) *Vertical Sync* from the 8350, normally highest priority, need to quickly change the Top of Page register for scrolling, to change the display before the new frame begins
- 4) *ACE, INS8250* — during serial block transfers this will take highest priority
- 5) *Keyboard* — the time to press the keys is much longer than the interrupt wait time so can be low priority
- 6) *A/D Converter* — time for conversion is 100 μ s so again can be low priority

Display RAM

The system requires a RAM with $24 \times 80 \times 10$ addresses, each of 8 bits (representing 7 dots + 1 attribute bit), and a cycle time of 640 ns/2 or 320 ns. Using static RAMs 19.2k bytes would require 40 ICs, whereas using dynamic RAMs 16 ICs are necessary, totalling 32k bytes. This leaves 13k bytes available as spare RAM.

Advantages of Dynamic RAMs

- Only 16, 16-pin packages instead of 40, 18-pin packages
- Less than \$10 for 16,000 bits
- Fast access and cycle times using the MM5290-2 (average cycle time is 320 ns). Even faster times with the 5V only 16k MM5295
- Standby current only 5% of operating current
- Less average power dissipation than for static RAMs

This means average power dissipation is $30\text{mA} \times 12\text{V} \times \frac{1}{2} \times \frac{1}{2} \times 16$ or 1.5W for all 16 packages (only one bank is accessed per cycle by the CRTC for half the dot cycle time). For 40, 4k \times 1 static RAMs, average power is $80\text{mA} \times 50\text{V} \times 40$ or 16W. Note that if the MM5295 5V, 16k \times 1 dynamic RAM is selected, power dissipation will be even further reduced, with access and cycle times about half the 3 rail version.

Disadvantages

- Not easy to interface to
- Need to be refreshed every 2ms — see “Refreshing of Dynamic RAMs”
- 3 supply rails needed, +12V, +5V, -5V, but these are already required for the 8080

Refreshing of the Dynamic RAMs

With 16k dynamic RAMs all 128 rows of every RAM have to be refreshed every 2ms maximum to maintain valid data. It is possible to manipulate the addressing of the CRT address bus to the dynamic RAM multiplexed address bus, so that there is no need for a separate refresh counter. This is because for any display row, the 8350 sequences all 80 characters, starting at line 0 and ending at line 9. Thus we can use the 3 least significant bits of the line counter outputs (A_{11} , A_{12} , A_{13} , from LC0, LC1, LC2) for three of the dynamic RAM row address bits, (corresponding to lines 0 to 7 of each display row), and the four least significant bits of the character position address (A_0 to A_3) for the remaining four RAM row address bits. See Figure 8.

Unfortunately, because 19k addresses are required, it is necessary to use two banks of RAM (8 RAMs in each bank), giving a total of $32k \times 8$. This leaves 13k bytes

available for scratch pad, display storage, and in-system emulation of programs. Therefore each row of this second bank of dynamic RAMs also has to be refreshed. By using address bit A_4 to select the bank, all rows of the dynamic RAMs are therefore refreshed every 32 characters, which in fact is eight lines, or in effect one row of the display. The worst case is when the 32 characters are split over two display rows. There is no problem during the vertical blanking because the 8350 still outputs incrementing addresses and LCGA continues to activate the control logic. So refreshing still continues during blanking. Thus the longest period any RAM row goes without a refresh cycle is $65\mu s$ per line \times 10 lines per row \times 2 rows = 1.3ms, which is still within the 2ms maximum at $70^\circ C$. In other words, dynamic RAM refreshing is automatically performed by the 8350 sequencing the address and no extra circuitry is required.

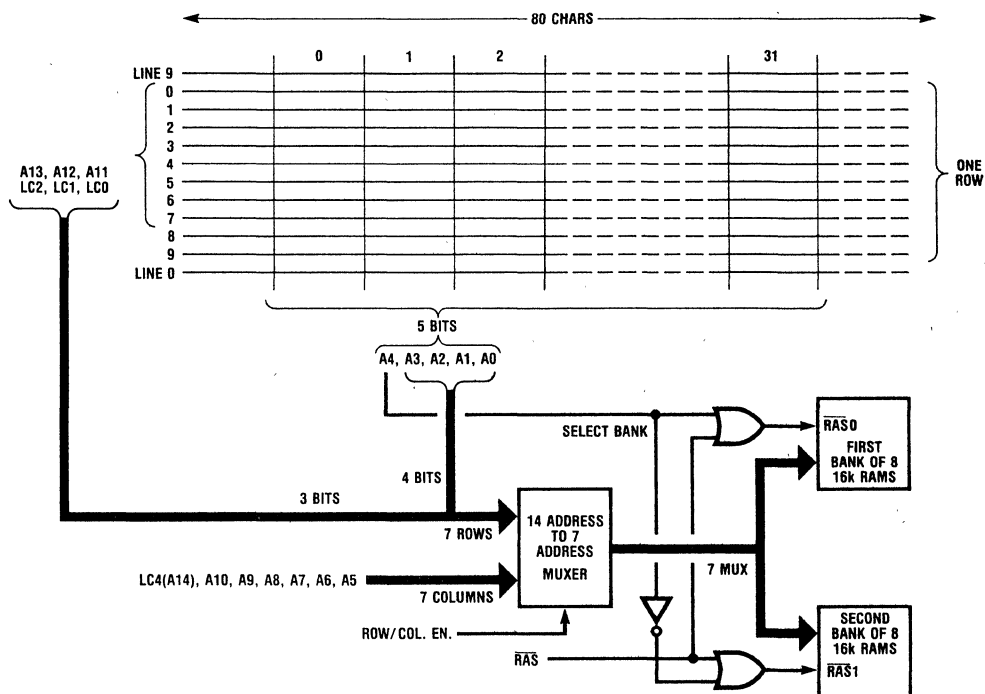


Figure 8. Automatic RAM Refresh

CRT Controller

A graphics/alphanumeric CRT Controller requires the following (See Figure 9):

- 1) All monitor signals provided — the 8350 provides Vert/Horiz sync and vertical banking
- 2) Cursor signal — the 8350 has cursor enable
- 3) Fast dot clock, a 7-dot cycle clock continuous, and a shift register clock only during display — the 8350 has dot clock, LCGA and LVSR
- 4) Line counter output 4-bit, tri-state — the 8350 has line counter output (but not tri-state)
- 5) Ability to set top of page, row start and cursor reg at any time — the 8350 can do this using LD REG, RA and RB inputs during the time the μ P is on the CRTC address bus. RA and RB can be data bus bits DB0 and DB1, and LD REG can be decoded from the address bus

- 6) 50 Hz or 60 Hz capability — the 8350 has a frequency select input
- 7) Increasing position address, tri-state — the 8350 has this, with a maximum enable/disable time of 30 ns

This parameter is important in this application where it is necessary to switch the memory from the CRTC address to the microprocessor address, and back to the CRTC address all in one 7 dot cycle of 640 ns. Other CRT controllers are not capable of enabling and disabling the CRTC address so quickly.

Hence the DP8350 requires no extra circuitry apart from a Quad Latch to disable the Line Counter outputs. The 8350 has internal ROMs which determine how many rows (24), columns (80), lines per row (10), and dots per column (7). Versions of the 8350 are available with other combinations.

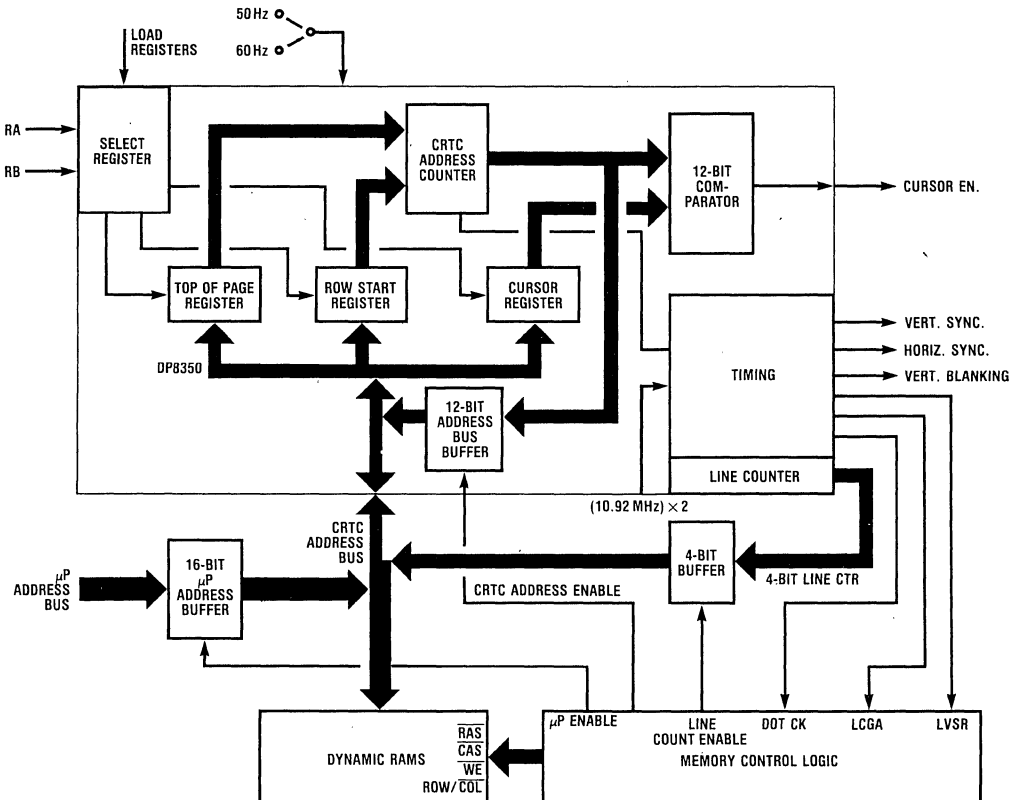


Figure 9. 8350 Block Diagram

System Timing

The standard timing for the dumb terminal type of application is shown in the timing section of Figure 1, with the microprocessor inactive during display time. This is undesirable for graphics applications where full use of the microprocessor is required for computations and peripheral control with very fast baud rate. To determine the timing sequence it is first necessary to calculate the CRTC frequency required for the dot clock.

$$\text{CRTC Frequency} = d \times [c + (\text{characters during horizontal blanking})] \times [(r \times l) + (\text{lines during vertical blanking})] \times (\text{line input frequency})$$

where d = dots per character,
 c = columns on display
 r = rows on display
 l = lines per row

For the standard 8350,
 $f = 7 \times (80 + 20) \times [(24 \times 10) + 20] \times 60 \text{ Hz}$
 $= 7 \times 100 \times 260 \times 60 \text{ Hz} = 10.92 \text{ MHz}$

This is too slow for the DP8224 which divides the crystal frequency by 9 to provide the clock to the microprocessor. The 8224 frequency can therefore be 21.84 MHz as in Figure 10, and this is divided by 2 to provide the 8350 dot clock of 10.92 MHz, or 91.6 ns per dot. A 7-dot cycle is 641 ns or 1.560 MHz. This is divided by 2, i.e., 780 kHz, to provide a clock frequency for the A/D converter.

The 8080 frequency is 21.84/9 MHz or 2.427 MHz. This frequency is also applied to the ACE to provide the clock for the Baud Rate divider. The baud rate is determined from 2.427 MHz/(16 x Baud Divisor).

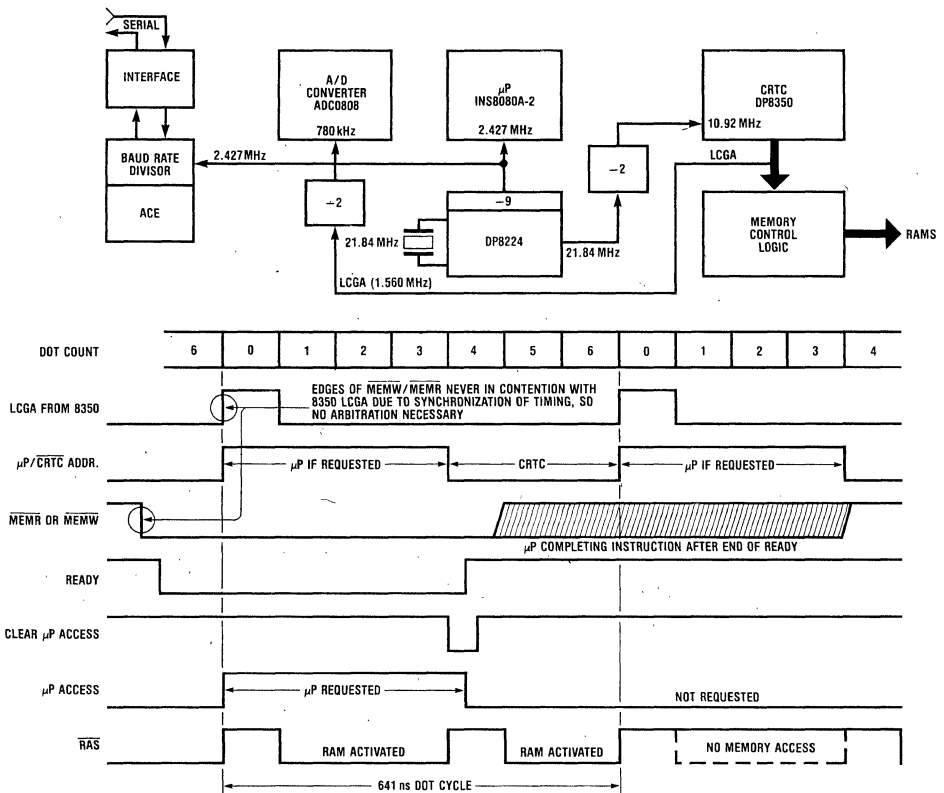


Figure 10. System Timing Control Circuit and Diagram

7 Dot Cycle Timing

Figure 11 shows how the 7-dot cycle time of 641 ns can be time multiplexed into two separate control sequences; Microprocessor and CRTC. It is necessary that the new 7-dot word to be displayed, is available at the commencement of the dot cycle shift. Therefore the 8350 must access the CRTC address bus for the second half of the 7-dot cycle, in fact for the last 3 dots of the cycle. This allows the time period taken by the first 4 dots to be used by the microprocessor, so that the microprocessor address output appears on the CRTC address bus for the first four dots, but only if a μP access is requested.

The CRTC 15-bit address is time multiplexed into 7 rows and 7 columns to be applied to the dynamic RAMs, using 2 DS3648 multiplexer-drivers, with bit A4 selecting the bank. It is therefore necessary to latch in first the rows with RAS (Row Address Strobe), and then the columns with CAS (Column Address Strobe), for both the μP half-cycle and the CRTC half-cycle. All the set-up

and hold times are met by the circuitry of Figure 12. If the μP is not requesting RAM access during its half-cycle, then RAS does not occur, although CAS still does. This is because RAS enables CAS internally in the dynamic RAMs, so that if RAS does not occur, the CAS has no effect and the RAM remains in standby mode. This is also the case in selecting the banks with RAS0 or RAS1.

In the second half-cycle, the CRTC always reads the RAM, so WE remains HI, but in the first half-cycle the μP may request a READ or WRITE. WE remains HI for READ, and for WRITE remains LO while RAS is low. Note that the 8350 outputs the address word two dot cycles in advance, and therefore it is necessary to latch and then hold the dot word for one dot cycle. It is then latched into the 7-bit parallel-in serial-out shift register. The 8th bit from the latch can be used as an attribute bit.

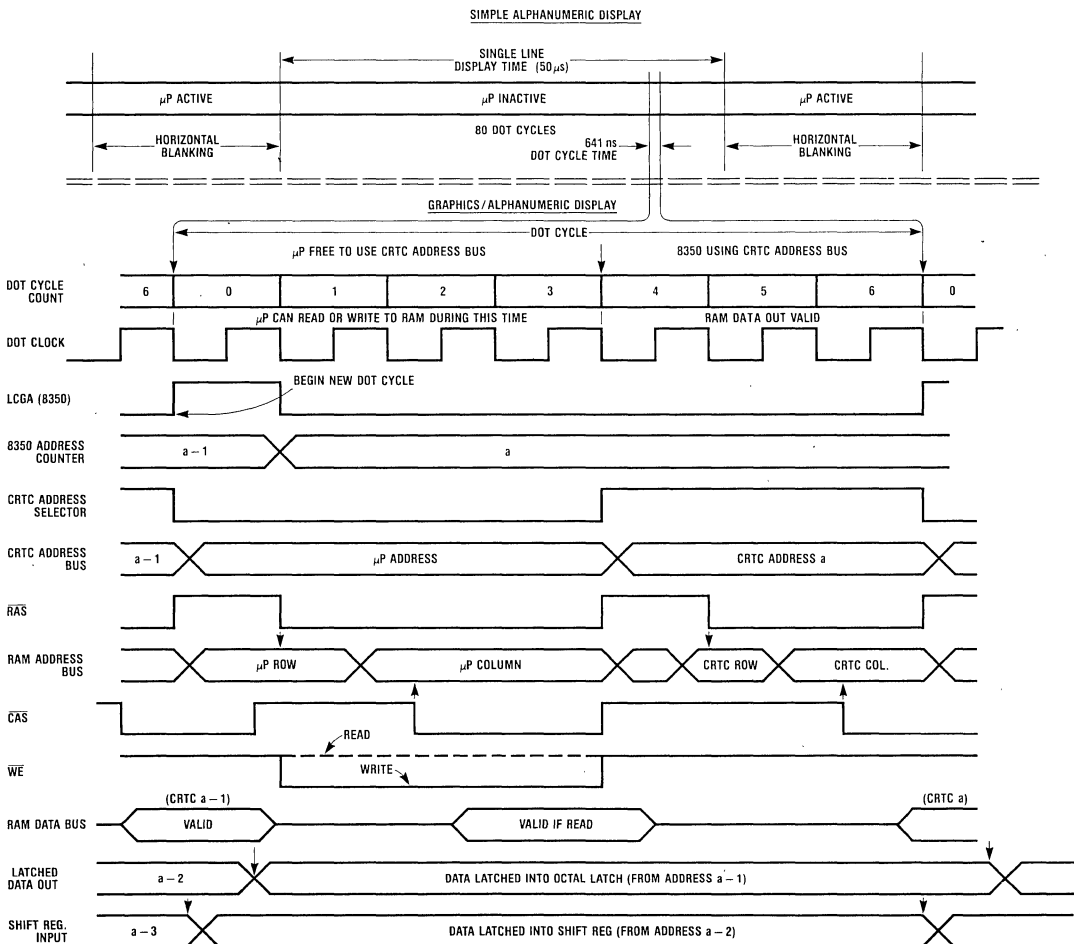


Figure 11. Memory Control Logic Timing Diagram

Figure 12 shows the Memory Control Logic required to correctly sequence the control signals and busses to the dynamic RAMs and associated components. The interfacing from the 8080 microprocessor (via signals MEMR and MEMW) is such that whenever the μP requests to read or write to the dynamic RAMs, the μP Access Flip-flops access the RAMs at the start of the next μP cycle. At the end of these four dots, the information has either been latched into an 8-bit latch (for READ), or written into the RAMs (for WRITE). The READY signal goes active at this time which ensures that valid information is read at the end of the μP cycle; refer to Figure 10. Also the fact that MEMR and MEMW occur at fixed intervals relative to the dot cycle signal, LCGA, means that system contention cannot occur. Therefore there is no need for arbitration between these two signals when a microprocessor cycle is requested.

This also applies when selecting the 8350 to change Top of Page, Row Start and Cursor. To select any of these 3 registers, the μP data bus bits D0 and D1 are connected to R_A and R_B to select the required register.

The information to be latched into the selected register has to be valid on the the CRTC address bus. Because this is time shared with the 8350 address counter, which outputs the incrementing display addresses during the second half of every 7-dot cycle, the CRTC register information has to be valid for the first half of the next dot cycle. The CRTC is selected with DS6/7 and MEMW, so that REGISTER LOAD occurs just after the CRTC register information becomes valid on the CRTC address bus. The 8350 spec requires that the address be valid 250 ns before REGISTER LOAD trailing edge (old data sheets do not state this), and that R_A and R_B are valid at the leading edge. Note that the 8350 internal address counter can be enabled or disabled within 30 ns of the ADDRESS ENABLE changing state.

All the Logic for Memory Control is Schottky, due to the very fast timing required in the system. Note that the cycle time of the CRTC half-cycle is 270 ns, which is less than the 320 ns specified for the MM5290-2. This parameter is specified at 320 ns for power dissipation reasons, and because the μP is not fast enough to use its half-cycle every 7-dot cycle or 641 ns, the average cycle time is greater than 320 ns

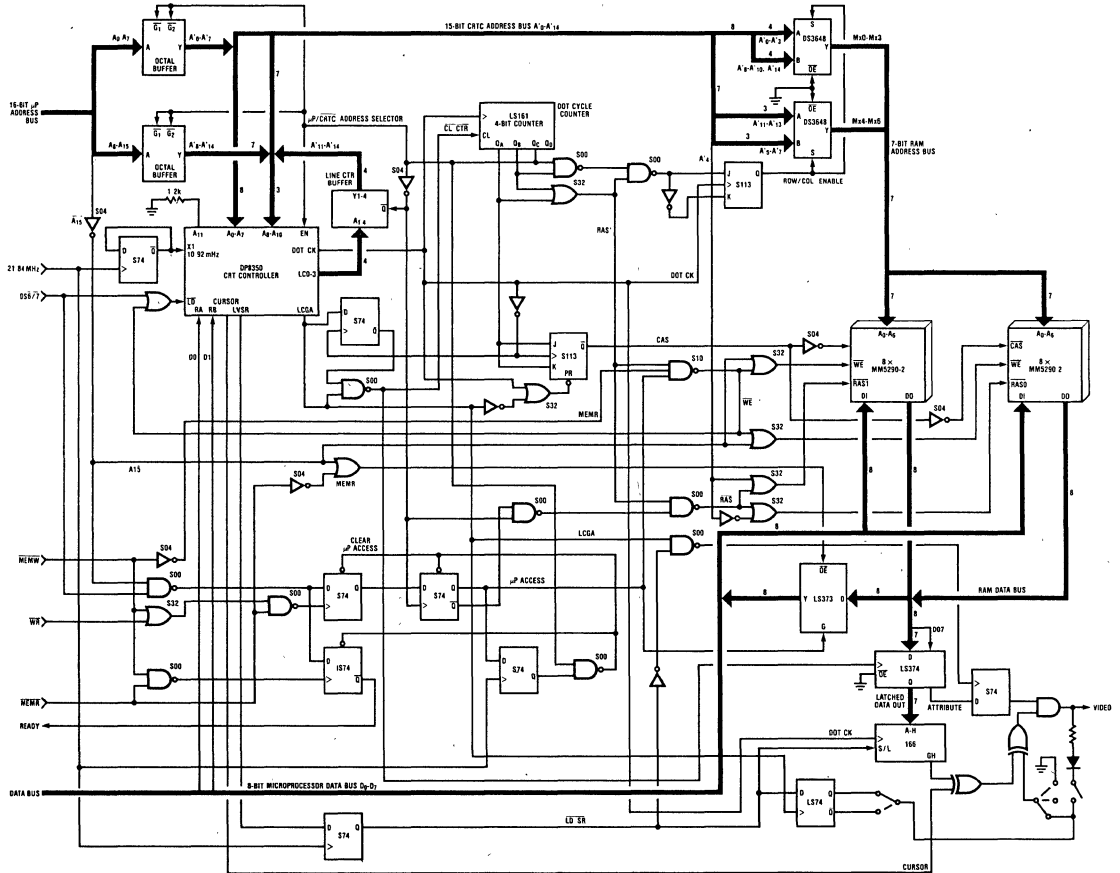


Figure 12. 8350 Graphics Memory Control Logic

System Configuration

Figures 13 and 14 together show the system block diagram. The peripheral components of Figure 13 are used with the microprocessor circuitry of Figure 14. The right hand half of Figure 14 is equivalent to the circuitry of Figure 12.

The LS138 address decoder is used for both I/O and memory addressing. Referring to Figure 15 address map, the peripherals are designated as I/O, and the EPROMs, ROM, CRTC and dynamic RAMs as memory. With address bit A15 HI, the 32k dynamic RAM block is selected. With address bits A14 and A15 LO, the LS138 outputs are selected. A11, A12, and A13 are decoded to

select which one of the LS138 outputs goes LO, so that when memory is addressed, each section is 2k bytes. This includes the CRTC which requires 4k bytes from 3000H to 3FFFH for 2 pages. The top four address bits select the CRTC and the remaining 12 address bits are latched into the selected register.

When addressing I/O, address bits A0-A7 also appear respectively on A8 to 15, so that with A6 and A7 LO, i.e., I/O address 00H to 3FH, each LS138 output is now 8 bytes selected by A3, A4, and A5. Bits A0, A1, and A2 are then connected as required to the peripherals, to select the addressed byte.

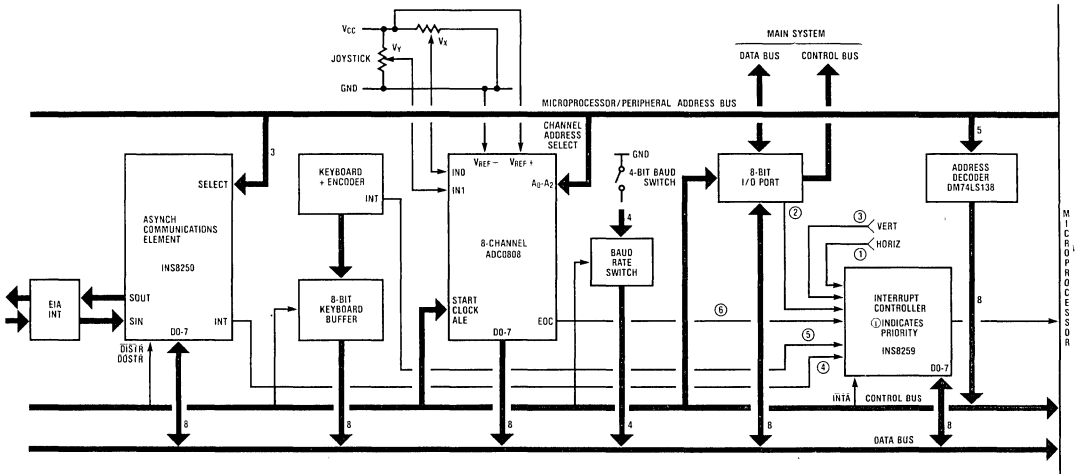


Figure 13. Interfacing to Various Peripherals

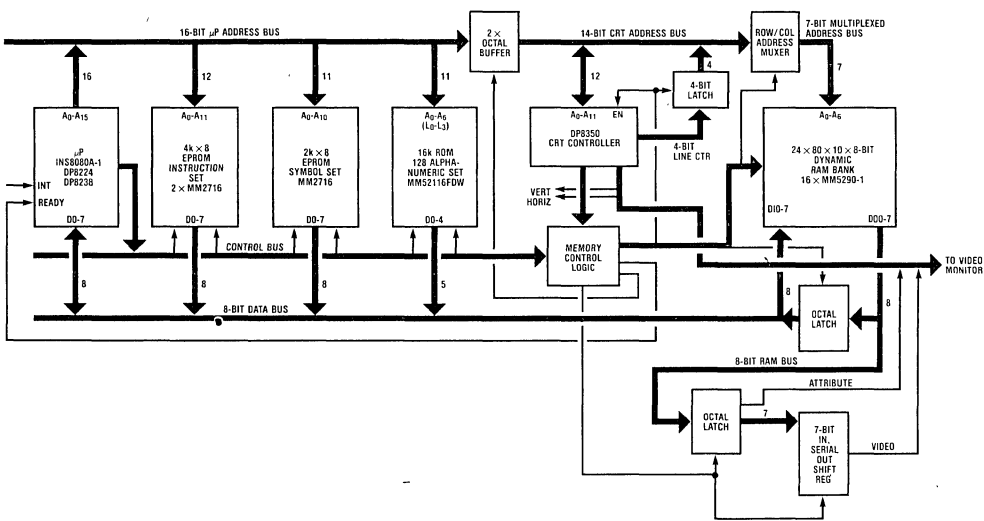


Figure 14. Complex Alphanumeric/Graphics/Symbol Display Terminal

Peripherals

I/O Port

IN 00H or OUT 00H select the 8-bit parallel I/O port, which basically is two octal latches with tri-state outputs. The 8 output bits may be connected to a master 8-bit data bus. When an external 8-bit data word is latched into the input octal latch, an interrupt causes this to be enabled on the μ P data bus, when acknowledged with the instruction IN 00H. To output to the master databus, OUT 00H causes the μ P data to be latched into the output latch and this also provides an external interrupt to the master system. The master can then read this data by enabling the output octal latch. Data can be transferred fast because the I/O port normally has the highest priority interrupt (IR 3 of the 8259), when required.

Interrupt Controller INS8250

This was also mentioned in an earlier section. At initialization, it is set up to remain in the fully nested mode, so that only higher priority interrupts may interrupt an existing interrupt. Otherwise a lower priority interrupt has to wait for the higher one to finish. Normally the horizontal sync interrupt to IR2 is masked off if there is no need to change ROW START or soft scroll display data off the screen line by line. The I/O address to select the 8259 can be either 10H or 11H; refer to the 8259 data sheet and the software to determine whether A0 is '0' or '1'. Each interrupt routine has to end with a SET END OF INTERRUPT instruction.

Keyboard

The instruction IN 18H reads the ASCII data on the keyboard after a keyboard interrupt has been acknowledged.

Serial I/O Using the ACE INS8250

The INS8250 with its associated EIA RS 232 interface allows serial data to be received or transmitted 8 bits at a time, with the instructions IN 20H or OUT 20H. The baud rate is previously determined as described in the software section. Other ACE registers may be accessed, by connecting A0, A1 and A2 of the μ P address bus to the same designations on ACE, so that ACE addresses are from 20H to 26H. During block transfers, such as dumping a picture on the screen into an external memory, or loading from the memory, the higher priority inputs can be masked off for fast transfers.

Baud Rate Switch

See 'Baud Rate' for application, the instruction OUT 28H will read the 4 switch positions.

A/D Converter ADC0808

This 8 analog channel, 8-bit A/D converter, has first to be initialized to commence a conversion on one of the channels. Address bits A0, A1 and A2 are used to select the channel, so that instruction OUT 3nH starts a conversion on INPUT n. The conversion takes about 100 μ s with the 780kHz clock, so the μ P can continue operating during conversion. The END OF CONVERSION signal then interrupts the μ P, which when acknow-

ledged reads the 8-bit data with the instruction IN 3nH, although n is not important in reading the A/D.

The A/D converter being only one 28-pin chip, is ideal for demonstrating the graphics capabilities of the system. For instance, an x-y joystick can be connected to INPUT 0 and INPUT 1, so that the movement of the joystick draws on the screen.

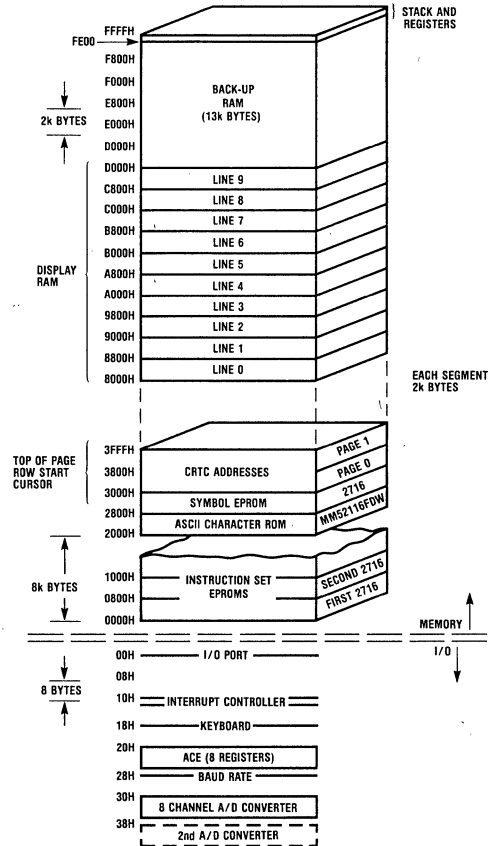


Figure 15. I/O and Memory Map

System Operation and Software

The software was developed purely for demonstration purposes to show the versatility and power of the system. All the software has been tested, but the system could be much more powerful with additional software. The 13k bytes of back-up RAM are also useful in this respect. The software was developed on National's STARPLEX™ Development System. The instruction set so far is just under 4k bytes, so two 2716's are used, but these may be replaced by 2732's if the chip select pins are reconnected, so that extension up to 8k bytes is possible with no extra IC sockets.

Parameter Definitions

The software is structured as in Figure 16. The philosophy was to make it versatile, easy to understand, and easy to modify or add to.

The registers are stored in the dynamic RAMs starting at FE00H in the non-display section. The Top of Stack is also in the RAMs at the highest location, FFFFH. This allows for about 240 nested two-byte PUSHes or CALLs, which is comfortable. Any register may easily be relocated merely by changing its address, similarly any new registers may be added to the list.

The addresses of the various memory and I/O locations are also listed and defined in the front section so these can be changed as desired.

For complete versatility, the display parameters are also listed in the front section so that any different value of parameters from those listed need be changed only in this section. The values of the parameters or constants are those of the standard DP8350 around which the hardware has been designed.

Thus by defining most parameters in the software once, at the beginning, the subsequent routines/subroutines will be valid for different applications and should not need to be altered, merely added to. Not many macros were used in order to save EPROM instruction space.

Interrupt Entry Locations

These are in 8-byte increments beginning at 0010H. The 16 bytes before this are saved for power-up initialization to disable interrupts and set Top of Stack.

Each interrupt location calls that interrupt subroutine. At the end of the subroutine, the system returns to output an END OF INTERRUPT to the 8259, and then returns to the original subroutine in progress when the higher priority interrupt occurred. If no interrupt was in progress, the program returns to the WAIT LOOP which enables all unmasked interrupts to the μ P.

Look-Up Tables

This has three sections. First, the BAUD RATE DIVISOR look-up table contains all the 16-bit divisors required for baud rates from 110 baud to 19k baud.

The next look-up table contains PROGRAM LABELS, used in the SEARCH FOR PROGRAM subroutine. The first row contains all the first characters of the program labels, the second row contains the second character, up to the fourth row contains the fourth character. Each program consists of four characters.

The third table is the address list so that once the SEARCH subroutine has located the desired label, it alters the program counter to the equivalent section of this table, which then calls up the program requested.

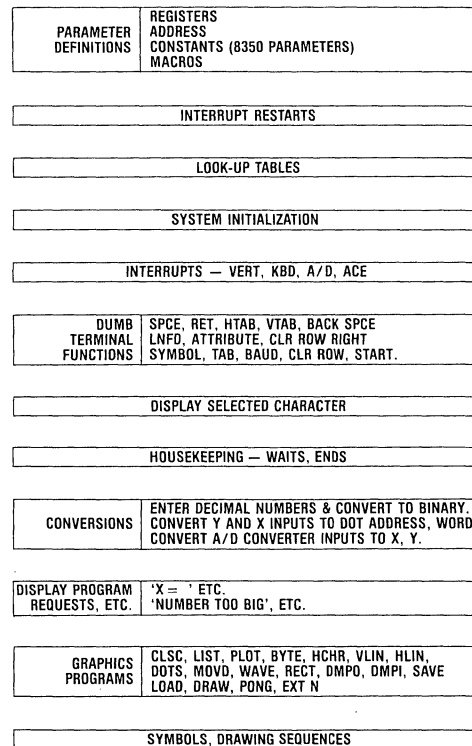


Figure 16. Graffiti — Software Structure

System Initialization

After disabling interrupts and setting Top of Stack, the 32k addresses of RAM are cleared one byte at a time, so that the screen is blank within half a second of switch-on. The cursor is then homed to the first character position. First the Top of Page register is set to 0 in the CRTC and then the cursor register is set to 0, both in the RAM and the CRTC. The column count is also reset.

The ACE is next set up including the baud rate (see Baud Rate section). Next, the Interrupt Controller is set up, and after this the system enters the WAIT LOOP system, enabling the interrupts to wait for an interrupt.

Interrupts

1) *Horizontal Interrupt* is normally masked off but may be unmasked for two reasons: either during scrolling, so that each row can be soft scrolled off the screen a line at a time, or during editing to delete a row, so that a jump in ROW START to the next row has to occur every frame at this new row. This new row must be loaded after horizontal blanking of the last line before the jump row is to begin.

Note that if the ROW START register is not loaded, each row start address is the last display address incremented.

2) *Port Interrupt* is normally masked off, but must be unmasked if transfer of data to a master system is necessary.

3) *Vertical Interrupt* is used for two purposes. One is to scroll the display by one row, once the scroll semaphore bit has been set in one of the associated subroutines, this is begun at vertical interrupt so that screen flicker does not occur. The other is to change a graphics display every frame so that smooth transition of a subject across the screen is attained. An example of this is the program PONG. The flow chart for Vertical Interrupt is shown in Figure 17.

4) *ACE Interrupt* is by far the most complex because data received by this chip then has to be operated on to determine what action to take. The flow chart for ACE Interrupt is shown in Figure 18. Assuming the interrupt is because ACE has received data available, the ASCII data is checked for a function input. If not a function, but a program is already in progress awaiting inputted data, then this character is saved in the Input Character register. If the character was entered while the cursor was in the first four positions of a row, then the character is saved in a register determined by the column position of the cursor. This saves the character to recall it in a look-up comparison later, while searching for a program. Unless the ASCII code was a function, the character is displayed in the cursor position (see Displaying Characters).

If the ASCII code entered is a function, then first CARRIAGE RETURN is checked for. If negative, then all the other functions are checked for and if positive, that particular function is executed. If the input is in fact a carriage return, then a check is made to see if the cursor was in the 5th position, signifying a four character graphics program has been requested. The system then goes to search in a look-up table for a program corresponding to the four ASCII characters entered in order. If a program is found, the system then calls the requested graphics program and executes it. If not, then a carriage return is executed.

5) *Keyboard Interrupt* in most systems is a simple subroutine, merely accepting the ASCII data word from the keyboard and outputting it to the ACE (see Displaying Characters).

6) *A/D Converter Interrupt* sets the A/D semaphore bit.

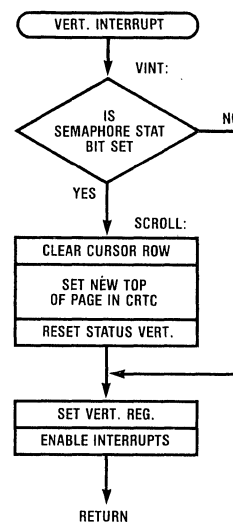


Figure 17. Vertical Interrupt Flow Chart

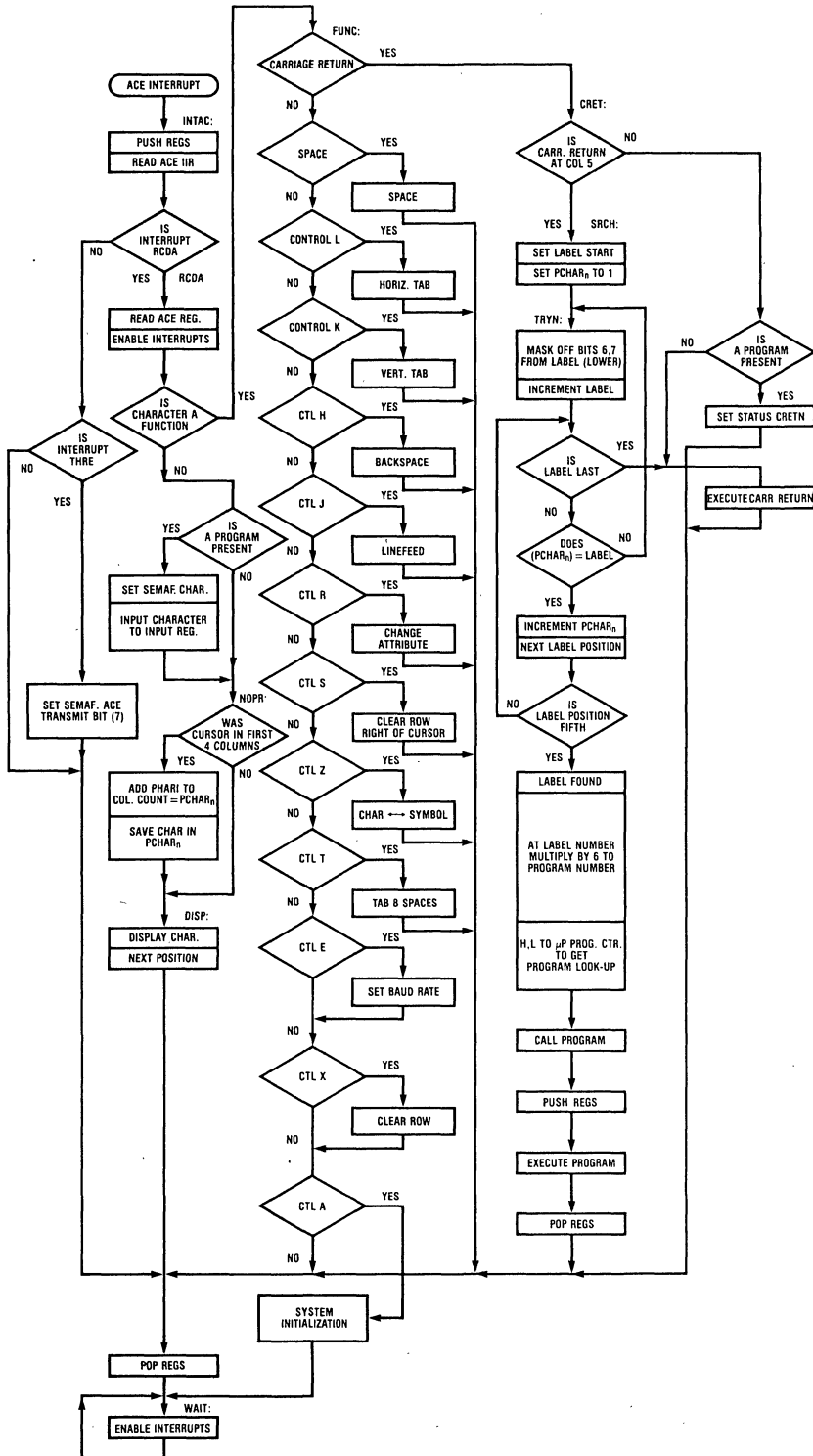


Figure 18. ACE Interrupt Flow Chart

Functions

A number of dumb terminal functions are available with the present software: carriage return, line feed, advance cursor, backspace, up cursor, tab 8 positions, clear row, clear row right of cursor, scroll up one row, and selecting attributes. Attributes available are half-intensity characters and character inversion. Each 7-dot location has its own attribute bit.

Baud Rate

The 4-bit BAUD SWITCH is used to select the BAUD RATE at switch on, or during operation if CTL E is entered. The μ P then reads the switch setting and loads the corresponding 16-bit BAUD RATE DIVISOR into the INS8250 Asynchronous Communications Element. Baud rates from 110 to 19k are available, and up to 56k is feasible if the 8080A-2 μ P is selected for fast data rates.

Displaying Characters

When a key is depressed, the keyboard outputs the ASCII code of the key selected, which is read by the μ P when the keyboard interrupt is acknowledged. The μ P then outputs the same ASCII data to the INS8250 ACE to be transmitted serially via the RS232 interface. This can be connected to a main computer, or an identical terminal, or back to the serial input of the ACE. When the ACE receives the returning 8 bits, it outputs a RECEIVED DATA AVAILABLE INTERRUPT or RCDA. The received data is then read by the μ P, which selects the ASCII character from the 128 character ROM (MM52116FDW) using the ASCII code as address. The alphanumeric character is copied line by line into the dynamic RAM in the position of the cursor.

Initially all RAM locations are '0' and the dots are written as '1', in a 7-dot word. See Figure 19. Then every frame, as the 8350 scans each line, the 7-dot word for each character position is latched from the RAM into the 7-bit shift register, and outputted serially during the next 7-dot cycle so that each '1' appears as a dot. The standard ASCII characters are displayed in a 7 line by 5 dot format or font. The 7 lines are copied line by line into the first 7 lines of the 10 line character field, leaving lines 7 through 9 as vertical spacing between characters. Data bits 1 through 5 are used for characters, leaving dots 0 and 6 as spacing between adjacent characters. The keyed character then appears on the screen and the cursor is incremented to the next position.

Additional Symbols

An additional 2716 EPROM with pre-programmed electronic symbols can be selected instead of the ROM, so that circuit diagrams can be drawn on the screen. Each symbol in the EPROM can be 10 lines of up to 7 dots so that each character may be continuous into the next — a necessity for circuit diagrams. The EPROM is selected by typing CTL Z on the keyboard and then a key, which can be either upper or lower case. This then displays the appropriate symbol in a similar manner to an alphanumeric character. To return to alphanumerics again, another CTL Z is required from the keyboard.

Two sequences are also stored in this EPROM, at addresses 1D00H and 1E00H. When either of these are called up by the program DRAW, a circuit diagram is drawn on the screen. This is an efficient way of storing

circuit diagrams. Each circuit sequence, requires about 200 bytes, which is not a lot to cover most of the screen, much less than the 19k bytes normally required to save every dot.

Although the symbol EPROM was programmed for electronic symbols, other kinds of symbols may be programmed into this EPROM, such as mechanical symbols.

Programming this EPROM is not easy. Assuming ASCII characters are to be used to select each symbol, then the addresses A_6, A_5, A_4 must be 100, 101, 110, 111 corresponding to ASCII codes 4XH to 7XH, where X is address A_3, A_2, A_1, A_0 . The 4 lines LC 3, LC 2, LC 1 and LC 0 go to address bits A_{10}, A_9, A_8, A_7 . The EPROM is selected with 00011B to $A_{15}, A_{14}, A_{13}, A_{12}, A_{11}$. In other words, to select the first line of character A (41H), the address would be 1841H, and for the second line 18C1H etc.

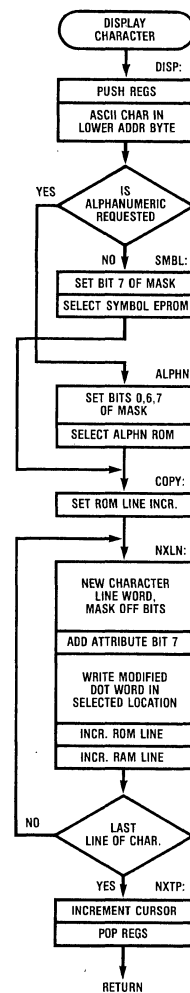


Figure 19. Displaying a Character

Locating the Position of a Dot

The standard DP8350 displays 80 horizontal characters for each of 24 rows, each character field comprising 10 lines of 7 dots. Thus there are 80×7 or 560 horizontal dots and 24×10 or 240 vertical dots in the display. Let the value of the horizontal dot position be x , where $0 \leq x < 560$, and y be the vertical dot position, where $0 \leq y < 240$. Refer to Figure 20.

If the x and y values are inputted to the microprocessor, it can then compute the character position, the line number and the dot position number. First, the Row Number r is INTEGER ($y/10$). This then has to be multiplied by 80 to produce the ROW START number. The Column Number then has to be added to this to obtain the Character Position Number, where the Column Position c is INTEGER ($x/7$). The line of the row is $(y - r)$, and the dot number is $(x - c)$ for the computed character position.

For the 8080 microprocessor, multiplication and division of numbers is laborious and time consuming. It is therefore easier to use the program subroutine shown in Figure 21 to compute the character position, line number, and dot number. A separate subroutine then computes the dot word from the dot number. This 7-dot word is then ORed with the word already in the computed dynamic RAM location. All this can be demonstrated using the program PLOT.

This computation takes an average of $300\mu\text{s}$ and a maximum of $500\mu\text{s}$. Hence up to 3,000 dots can be plotted per second for any values of x and y to create a graphics display.

A good demonstration of the graphics capability is to connect an x - y joystick to two analog inputs of the A/D converter and by selecting the program MOVD (move dot), moving the joystick. The joystick can be moved quickly from one extreme to another and all dots on the way are displayed. This program can also use a dot as the cursor, using the joystick to select its position, and then to depress keys whenever a desired character is required at the character position of the dot.

Dot Word Transfers

With the use of the ACE, it is possible to unload the contents of the RAM into either an identical terminal to copy the display, or to store it in a main computer. It can then be recalled from the computer at a later date and re-loaded into the RAM to be displayed. Or if desired, sections of the display can be transferred. Copying from or to the display can be fast, because 7 dots are read or written at a time. An example of this is to use the programs SAVE and LOAD. A section of the display (such as a circuit diagram) can be saved in the back-up RAM, and then loaded back on to the display in a different area. The diagram appears almost instantly.

This extra 13k bytes of back-up RAM can also be used as additional memory for in system emulation of programs, or for powerful computing capability for graphics calculations.

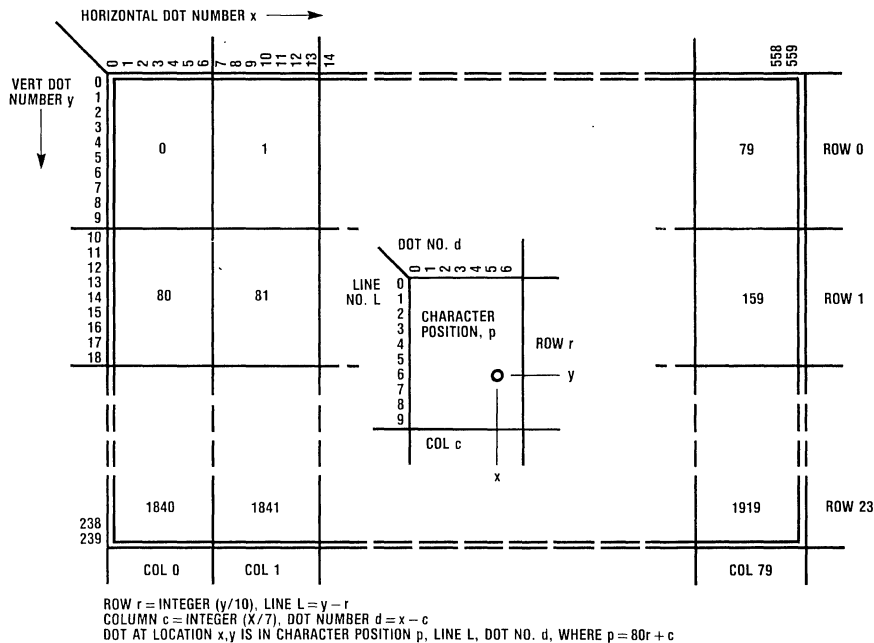


Figure 20. CRT Display/8350 Character Address Positions

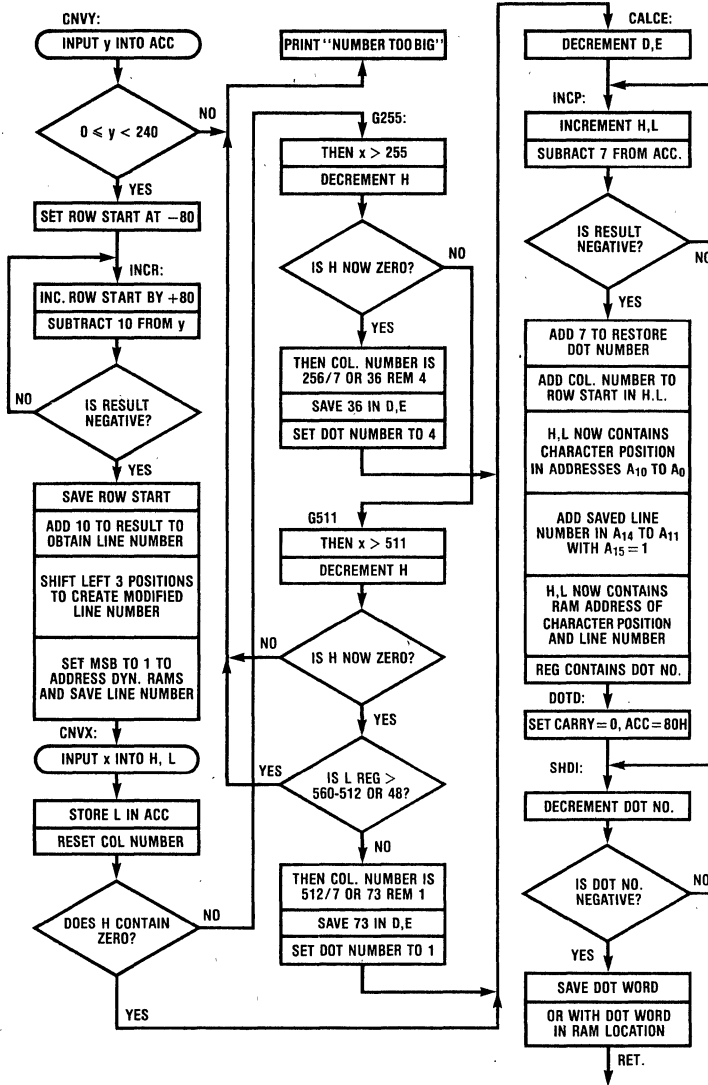


Figure 21. Flow Chart to Add Dot x, y to Display

Graphics Programs

To perform various graphics functions it was decided to select the necessary software with four letter program labels, followed by a carriage return. As long as the label derived starts at the first column of a row, the program requested is called up and executed. Some programs request information from the operator. PLOT is an example of this, where the values Y1 and X1 are requested by the display. The user types in the desired values in normal decimal, signifying the end of the number with a carriage return. After both y and x have been entered, the program continues, in this case plotting a dot at Y1, X1.

Conversion of Entered Decimal Numbers

The conversion of the decimal numbers entered and saved in the Input Number registers, is performed by the subroutine ENTR. First the last decimal number entered (obviously units) is tested for ASCII number units and then saved. The second number (tens) if entered, is then tested and decremented until 0 is reached, and each decrement, 10 is added to the total number. Then the third number (hundreds) is tested and decremented to 0, each time 100 is added to the total. At the end of the conversion, H, L register contains the total number in binary. This is then saved in the respective register.

Conversion of 2 Hexadecimal Characters to an 8-Bit Word

This subroutine takes 2 ASCII characters each in the range 0 to 9, A to F, and converts them to a binary word. First, the 3 ASCII code bits are masked off the number first entered. This is shifted left 4 times and added to the masked off 4 bits of the second number entered. This 8-bit word is now 7 dots plus one attribute bit. With this method, it is easy to write/read words quickly on to the display, in the selected location. This can be demonstrated with the program DMPI (dump-in) as in the next two sections.

Display Loading

The starting address is first entered (anywhere from 8000 H to FDFFH) by keying in the first two hex numbers when requested by B = (byte), no carriage return, then the last two hex numbers. This is repeated for the end address. The bytes are then entered 2 ASCII characters at a time. If the addresses are between 8000H and CFFFH, the words will appear on the display. For example, 7F will appear as 7 dots, or 83 will appear as the 2 right-hand dots with attribute. In this way a picture can be loaded on to the display.

Use of Back-up RAM

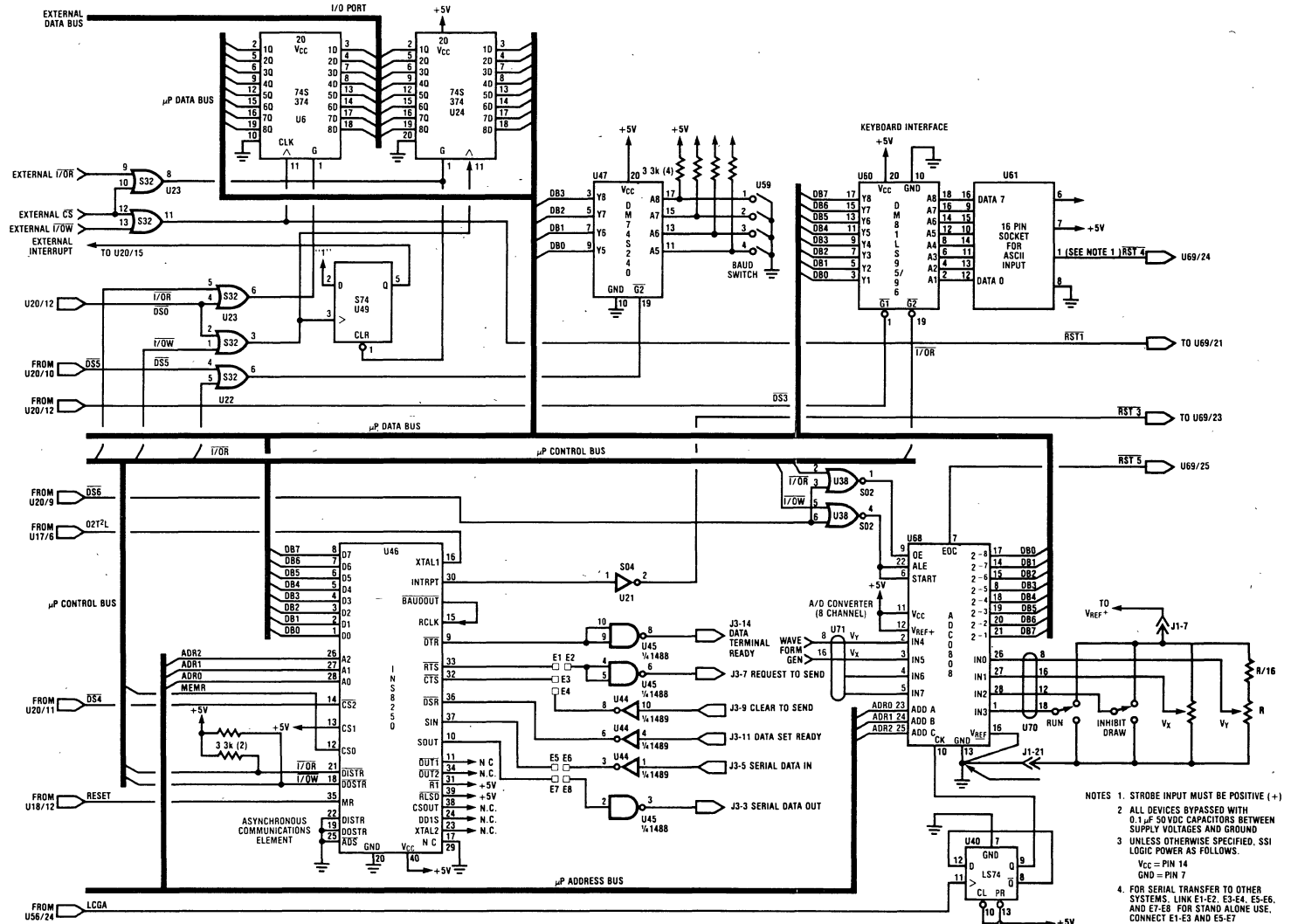
If the DMPI addresses are between D000H and FDFFH, the information is stored in the back-up RAM. This is useful for in-system emulation, for example. By calling up the program EXT0 (External 0), if a program has previously been loaded in the back-up RAM, starting at address D000H, this program will then be executed after EXT0, carriage return. Another use of this section of RAM is the storage of different sequences of circuit diagrams other than those in the symbol EPROM. The program DRAW can then call up the starting address.

Additional Software

The power and versatility of this system is easily demonstrated with the existing software. This can be added to as required with new software, calling up existing subroutines where possible. Up to 4k bytes of additional software can be incorporated without any hardware modifications (other than moving two links to select 2732s instead of 2716s).

Conclusion

So using all National Semiconductor ICs, at a cost of a few hundred dollars, the hardware for an intelligent terminal with full graphics capability can be fitted on one BLC80/SBC80 size card. The design is easily expandable to systems requiring color. The biggest modification is to the memory: instead of one bit per dot, 3 bits are required for blue, green, and red, to give 8 possible combinations per dot. A small number of extra logic ICs are required, as are minor additions to the software. To select the color, a CTL key can be used followed by the code for the color. This color will then be written until changed by the CTL key. A different CTL key followed by a number could previously have set the background.

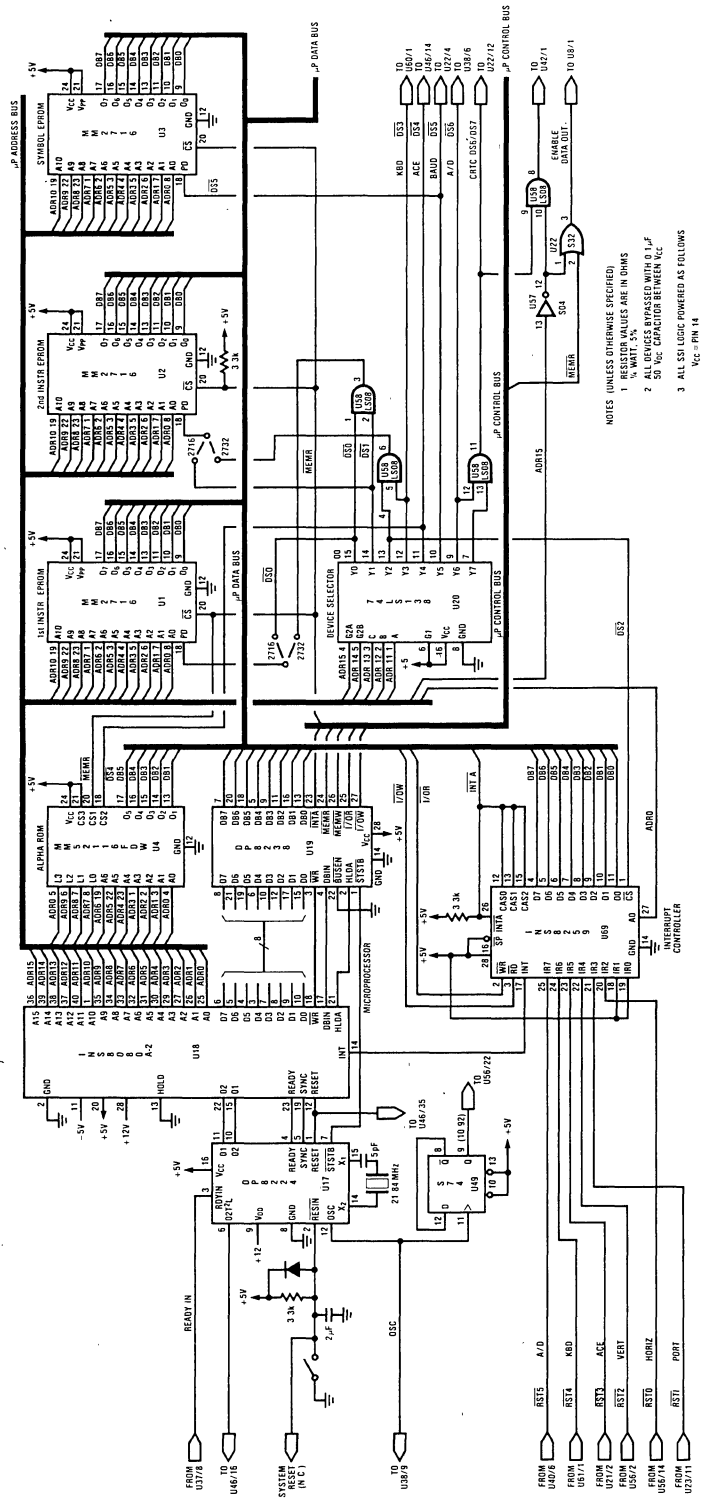


- NOTES
1. STROBE INPUT MUST BE POSITIVE (+)
 2. ALL DEVICES BYPASSED WITH 0.1µF 50VDC CAPACITORS BETWEEN SUPPLY VOLTAGES AND GROUND
 3. UNLESS OTHERWISE SPECIFIED, SSI LOGIC POWER AS FOLLOWS.
V_{CC} = PIN 14
GND = PIN 7
 4. FOR SERIAL TRANSFER TO OTHER SYSTEMS, LINK E1-E2, E3-E4, E5-E6, AND E7-E8 FOR STAND ALONE USE. CONNECT E1-E3 AND E5-E7

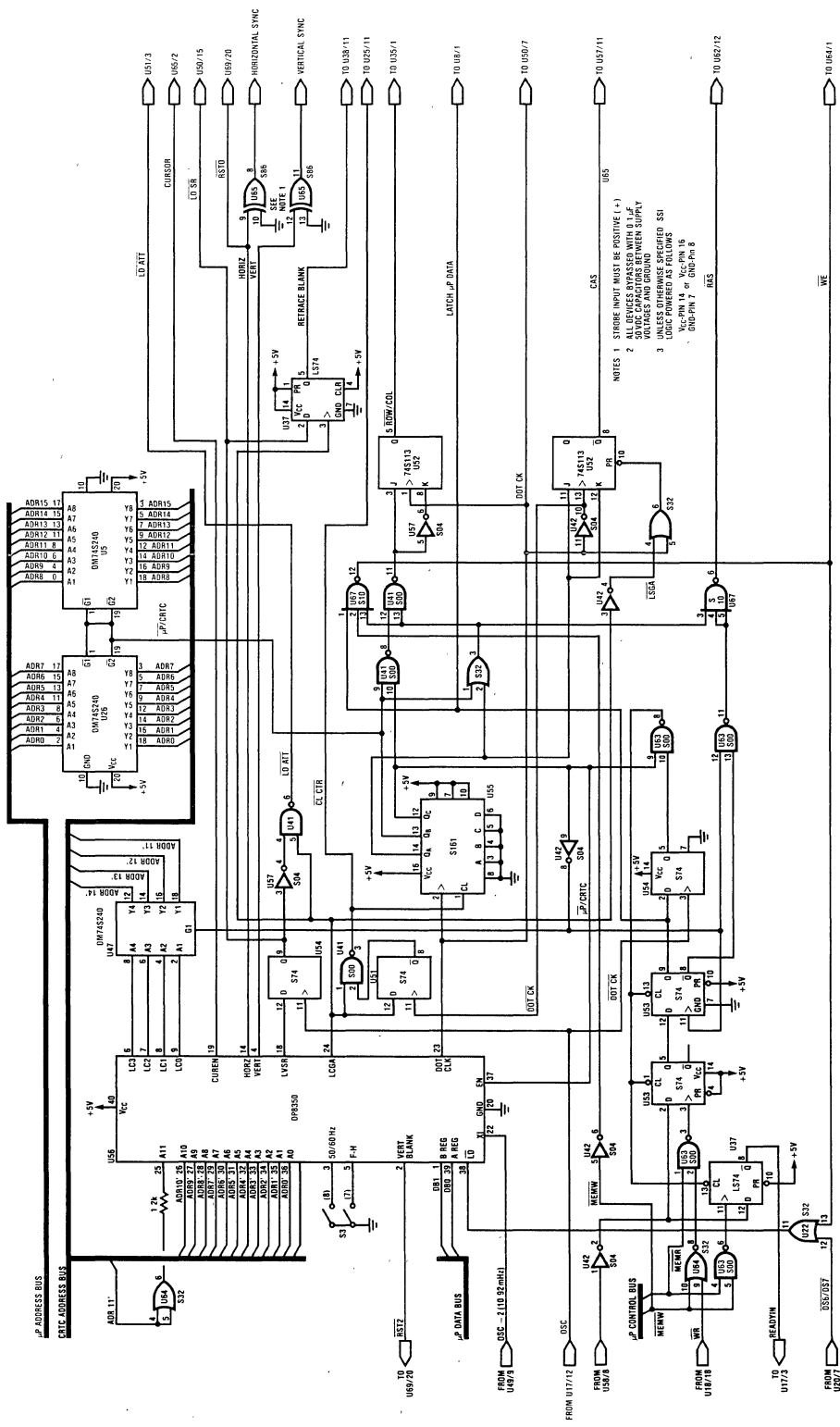
DP8350/INS8080 Full Graphics Video Terminal System — Peripheral Interface Block

5-70

DP8350/INS8080 Full Graphics Video Terminal System — CPU, EPROM and Interrupt Block



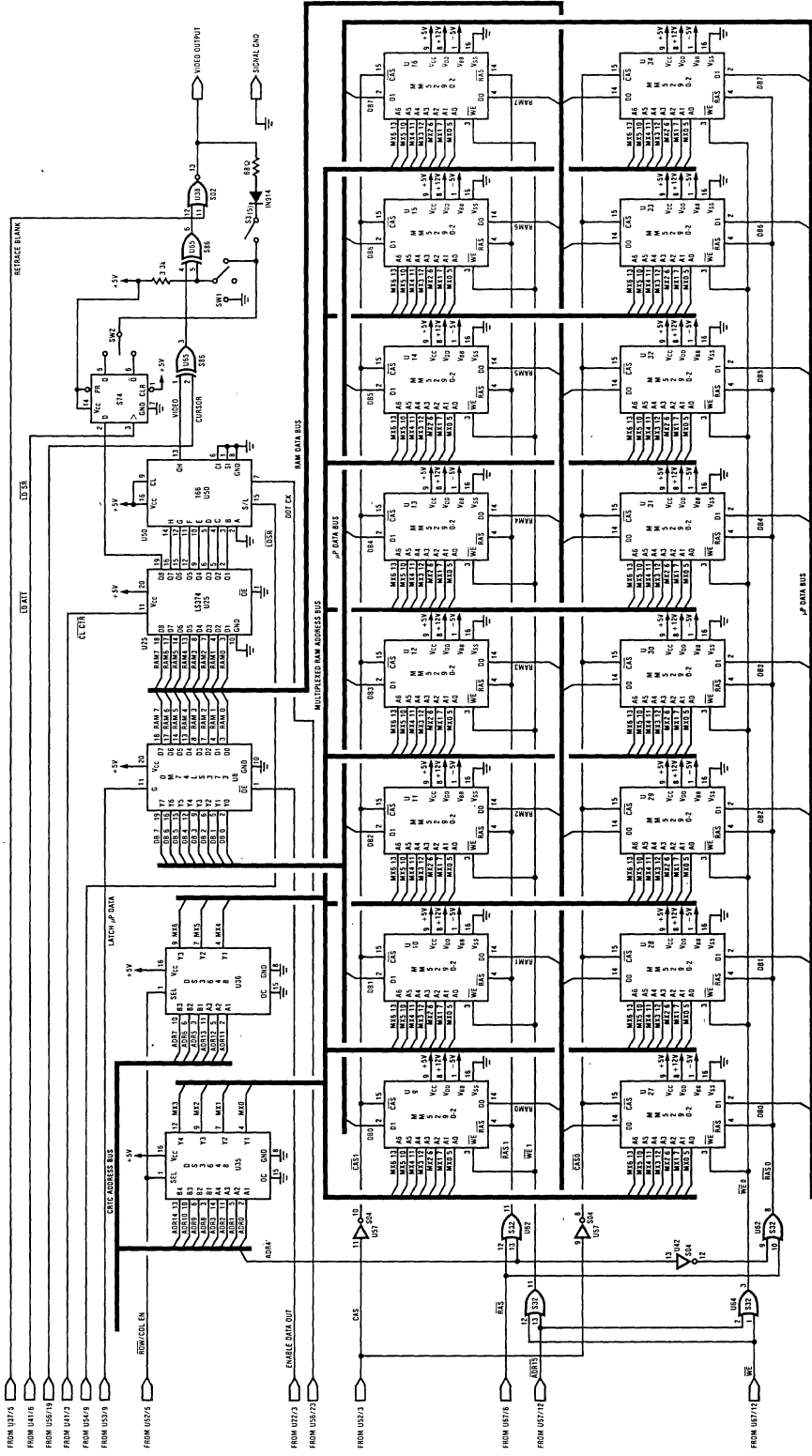
- NOTES (UNLESS OTHERWISE SPECIFIED)
1. ALL LOGIC DEVICES ARE IN DWMs
 2. ALL DEVICES W/PASSER WITH 0.1µF 50% VOLT CAPACITOR BETWEEN VCC
 3. ALL SSI LOGIC POWERED AS FOLLOWS
VCC - PIN 14
GND - PIN 1



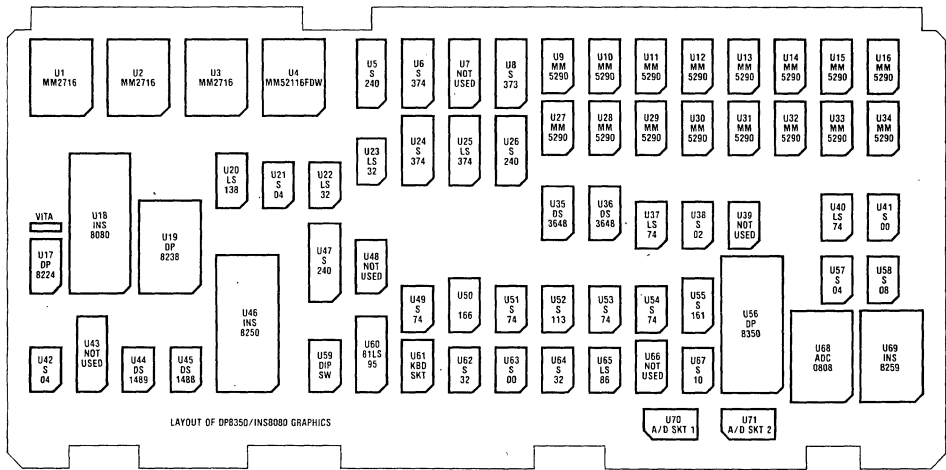
- NOTES: 1 STROBE INPUT MUST BE POSITIVE (+) 100 NS PULSE
 2 ALL LOGIC SIGNALS MUST BE POSITIVE (+) LOGIC VOLTAGES AND GROUND
 3 LOGIC POWERED AS FOLLOWS: SSI
 1/2-PIN 14 = GND-PIN 15
 GND-PIN 7 = GND-PIN 8

DP8350/INS6080 Full Graphics Video Terminal System — Memory Control

DP8350/INS8080 Full Graphics Video Terminal System — Memory/Video



NOTES 1 ALL DRIVES SUPPRESSED WITH 0 LUF CAPACITOR BETWEEN SUPPLY VOLTAGES
2 ALL SEL LOGIC GATES POWERED AS FOLLOWS
3 GND PIN 1



Layout of DP8350/INS8080 Graphics

Present Capabilities of Alphanumerics/Graphics System

Dumb Terminal Functions

- ** All 128 ASCII Characters Displayable
- ** Space
- ** Carriage Return
- ** Horizontal Tab (→) or (CTL L)
- ** Backspace (←) or (CTL H)
- ** Linefeed (↓) or (CTL I)
- ** Vertical Tab (†) or (CTL K)
- ** Select/Deselect Attribute (CTL R) with SW-1 or S-3
- ** Tab 8 Spaces (Tab) (CTL T)
- ** Clear Cursor Row (CTL X)
- ** Clear Row Right of Cursor (CTL S)
- ** Initialize System (CTL A)
- ** Select Baud Rate from 110 to 19,200 Using S-1 and CTL E
- ** Scrolling Upwards

Non-Standard Character/Symbol Selection

- ** By selecting CTL Z, symbols can be displayed for each key of the keyboard, including shifted and control keys. Also can deselect back to standard ASCII characters with CTL Z.

Graphics Programs

- *CLSC: Clears screen only, leaving 13k back-up RAM unaffected.
- *LIST: Lists all graphics programs.
- *PLOT: Plots a dot at X, Y. X is the number of horizontal dot positions from the left of screen, from 0 to 7×80 for the 8350, i.e., $0 \leq x \leq 559$. Y is the number of vertical dots from the top of the screen, from 0 to 10×24 , i.e., $0 \leq y \leq 239$. The operator keys in the decimal values of Y and then X when requested by the display.
- *VLIN: Draws a vertical line between Y1 and Y2 at X. These values are entered decimally by keyboard when requested by the display.
- *HLIN: Draws a horizontal line between X1 and X2 at Y1. These values are entered decimally by keyboard when requested by the display.
- *RECT: Draws a rectangle linking lines X1, X2, Y1, and Y2.
- *PONG: Bounces a dot around the screen between the four walls of the display.
- *DRAW: Draws a diagram on the screen from a sequence of operations saved in ASCII code in memory. The START address of the sequence is determined by the first four hexadecimal characters entered on the keyboard. The address 1D00H selects a DC voltage restoring circuit sequence located in the symbol EPROM. Address 1E00H selects a logic circuit and waveforms. Test sequences can be loaded into back-up RAM using program 'DMPI' at the starting and end address entered. This start address is then called up by 'DRAW.' The end address must contain 0 (zero).
- *SAVE: Saves in the back-up RAM a section of display contained within rows R1 to R2, and columns C1 to C2. These values are entered decimally by keyboard when requested by display. The start address in the back-up RAM is selected by the first four hexadecimal characters entered on the keyboard.
- *LOAD: Loads from the back-up RAM to a section of display bounded by R1, R2, C1, C2. These values are entered decimally by keyboard when requested by the display. The back-up RAM start address is selected as in SAVE.
- *DOTS: Plots N dots on any line Y1 at positions X1, Y1; . . . XN, Y1; and then any new line entered in decimal by the operator. Ends the program by entering 0 (zero) when the next Y1 is requested.
- *MOVD: Uses the 8-channel 8-bit A/D converter to monitor the voltages on a X-Y joystick, an inhibit-draw switch, and an exit-program switch. In the DRAW mode consecutive dots are plotted to create a picture as described by the movement of the joystick. All these input signals are connected to the first A/D socket. In the inhibit DRAW mode the dot is moved around by the joystick as a cursor, and by keying in from the keyboard the desired character, this character will appear in the character field of the dot. This moving dot can be used to erase existing dots, or erase characters by keying 'SPACE' in the desired position. To exit the program, set the EXIT program switch in EXIT-DRAW mode with the Inhibit-Draw Switch in INHIBIT.
- *WAVE: Uses the A/D converter to create waveforms on the screen when the signals are connected to the second A/D socket.
- *DMPO: Unloads any part of RAM to an external system starting at an address keyed in by the operator in hexadecimal characters (four) and ending at another similarly entered address. The RAM is unloaded 7 dots at a time per line of character and converted to two ASCII characters and then transmitted serially.
- *DMPI: Loads any part of RAM from an external source (or the keyboard) starting at an address selected by the first four hexadecimal characters entered on the keyboard and ending at another similarly entered address. The RAM is loaded 7 dots at a time per line of character, keyed in by two hexadecimal characters, for each word. The addresses selected can be display addresses 8000H to CFFFH or back-up RAM addresses D000 to FFFFH (warning: FE00H upwards are registers and FFFFH downwards are stack). Thus a complete picture could be loaded on to the display. Alternately a program could be loaded into back-up RAM at EXT0 (D000H), EXT1 (D800H), EXT2 (E000H), or EXT3 (F000H). the characters 'EXTn' can then be typed in on the keyboard and this will then select the instructions beginning at address EXTn. Thus in-system emulation is easily accomplished.
- *EXT0: Executes a program beginning at RAM address D000H. The program must previously have been entered using DMPI selecting D000H as the starting address.
- *EXT1: As EXT0 but starts at D800H.
- *EXT2: As EXT0 but starts at E000H.
- *EXT3: As EXT0 but starts at F000H.

Software Design for a High Speed (38.4 kbaud) Data Terminal

National Semiconductor
Application Note 270
Wong Hee
Nick Samaras
February 1982



INTRODUCTION

This application note describes a high speed CRT terminal designed around the DP8350 CRT controller and the INS8080 microprocessor. The hardware is a modified version of the circuit described in Application Note AN-199. The software was redesigned and optimized for terminal speed and function. In its present form it is upwards compatible with the Hazeltine 1500 video terminal and has a limited graphics capability. Furthermore, it is able to communicate with a host computer via an RS-232 port, at 38.4 kbaud, without using fill-in characters or handshaking. One 2k by 8 EPROM contains all the software required to implement the terminal. An optional EPROM can be used to add features such as menu display or to transform the terminal into a calculator (in the local mode). The absence of the second EPROM does not affect the operation of the terminal as the software checks for its presence.

DATA TERMINAL FEATURES

- Modes: remote/local
- Limited graphics
- Window scrolling
- Line transmitting and local editing
- Hazeltine 1500 compatible*
- Video display: two pages, 24 x 80 characters/page
- Upper/lower case
- Scrolling plus screen roll up/roll down
- Cursor: blinking (two rates)
- Line, character insert/delete
- Attributes: dual intensity/inverse video
- Full duplex RS-232 port; 110-38400 baud
- Keyboard input: 7-bit parallel
- Full cursor control and addressing
- Cursor enable/disable
- Single board (BLC/SBC) compatible design

*The majority of the software written for the Hazeltine 1500 will run with no modification. However, there are differences.

UNIQUE FEATURES

Graphics Capability: The graphics capability of this terminal, although limited by the number of symbols (34), proves to be very helpful. Typical uses include digital waveform generation (e.g., logic analyzer display), and graph oriented displays such as histograms. A graphics menu is available in the local mode. Entering !Q[†] from the keyboard will result in a two line menu display. Line 23 displays upper and lower case characters, while line 24 displays the corresponding graphics symbols (see *Figure 3*). In local, entering !B will switch the terminal to the graphics mode; the ESC key can be used to exit. In remote mode, the format requirements for graphics display generation are summarized by the flowchart shown at the bottom of this page.

The same flowchart can be used in local, if the "lead-in"^{††} block is omitted.

Typical transmission sequences are:

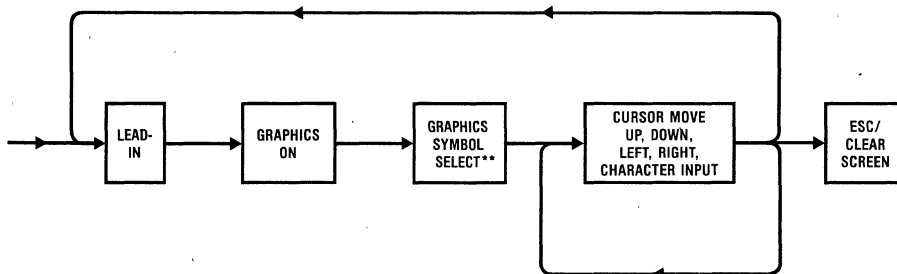
```
7E, 02, 42, 10, 1B
7E, 02, 63, 10, 10, 10, ..., 10, 1B
7E, 02, 42, 8, 8, 8, 4A, 7E, 0C, 7E, 0C, 1B
```

All the graphics symbols, along with the upper and lower case characters, are coded into one 2716 EPROM. As a result, both the character set and the graphics symbols may be customized. The total number of available fonts is 128. The field on each displayed character is 7 rows by 10 columns. The alphanumeric symbols occupy a 5 by 7 sub-field typically, except for those requiring descenders; they occupy a 5 by 9 section, while the graphics symbols utilize the whole 7 by 10 field.

Transmit: The data terminal can transmit one line of text upon receipt of the 14H code from the keyboard in local mode. Alternately, the host CPU can request transmission by sending 14H prefixed by the 7E lead-in code.

[†]Note that ! indicates a control key entry.

^{††}Lead-in code: 7E.



** Includes the ASCII characters A-Q, a-q, space and DEL.

The same function can be used in a relatively unconventional way when programming in BASIC. The majority of BASIC interpreters used in small business systems or home computers incorporate a line-oriented editor, almost adequate for most of the tasks they have to perform. The basic problem with such editors is that they cannot change the flow of the program easily. In other words they cannot change line numbers. This is a shortcoming, as it is both annoying and tedious having to retype segments of text in order to change the program flow, just because the editor cannot handle altering line numbers only.

This terminal offers an efficient solution to this problem. Simply stated, it allows changing line numbers only. Here is a brief description of a typical sequence leading to text and/or line number modification. Let us assume that a BASIC interpreter is used and that the program that needs to be changed is in memory. Using the list command, the program lines to be modified can be displayed. Now, while in the Command Mode of BASIC, the terminal is switched to local. The user has effectively at his disposal a screen-oriented editor. The cursor can be moved about and text changed as desired; that, of course, includes line numbers. When the editing is completed, the user positions the cursor on the line that was altered and types `IT`. In response, the cursor scans the line, inverting the attributes. At the same time the line is transmitted to the host CPU in the same order as it was scanned, from left to right. Attribute inversion serves as feedback to the user. After the last character of each line has been transmitted, the cursor returns to the beginning of the following line. As a result, consecutive `IT` keyboard entries transmit successive lines. Thus, altering the flow of a BASIC program involves entering the local mode, changing line numbers, transmitting the modified program lines, and switching back to on-line operation. All this can be accomplished at a fraction of the time usually required otherwise. Finally, entering similar lines of text such as the ones found in "PRINT" statements, can be accomplished easily by switching to local, typing the first line and transmitting it; then moving the cursor up one line, changing the line number along with parts of the text that are different, retransmitting the line, and so on. In this way the user can create a long program segment while operating repetitively on one line.

Insert/Delete with Range: This is a rather unusual function that can assist in generating pseudo "screen window" effects. Specifically, a pre-selected number of display lines can scroll while the rest of the display remains fixed. Each "window" is defined as N lines by 80 characters, where: $1 < N < 48$, counting from the current cursor location to the end of page. The brief BASIC program that follows demonstrates the use of this function. In this example the display lines 1 through 4, and 19 through 24 remain "frozen". The message (100 lines long) is displayed on lines 5 through 18, demonstrating the scrolling of a section of the display.

```
100 PRINT CHR$( &H7E) + CHR$( &H11) + " d";
110 FOR I = 1 TO 100
120 PRINT CHR$( &H7E) + CHR$( &H1D) + CHR$( &H49)
    + CHR$( I2);
130 PRINT, "WINDOW SCROLLING LINE:", I,
    CHR$( &HOD);
140 NEXT I
```

80 Character Software FIFO: This is one of the key items that allows terminal communication at 38.4 kbaud without handshaking. An 80 character first-in, first-out software buffer is used. The incoming characters are stored temporarily in this buffer, while the microprocessor is servicing interrupts. As time becomes available, the characters are retrieved from the FIFO and processed. That includes performing a terminal function or moving an ASCII character to the video memory. The software allows for a large number of concurrent service requests such as row start, keyboard, as well as multiple ACE interrupts.

Fast Service Routine for Row Start Interrupt: Conventional row start address look-up and loading are not done during the row start interrupt time; instead, a simple row counting routine is used. The terminal count (a software counter) generates a triggering signal for video RAM wrap-around address loading. The use of this technique improves the system throughput substantially. Cursor and Top of the Page address loading (i.e., writing to the appropriate DP8350's registers) is done during the vertical retrace interval.

Keyboard Controlled Mode Selection: The operating mode of the terminal can be selected from the keyboard. To aid the user in identifying which mode the terminal is in, two cursor blinking rates are used. The low rate indicates remote mode; a high rate indicates local.

Other functions that can be selected from the keyboard are:

- 1) Upper/lower case. The default mode upon power up is determined by reading the SW3 switch setting.
- 2) Next page. A software switch that selects for display page one or two.

Read Cursor: In the local mode the present cursor location can be displayed on line 24, columns 79-80. For example, if the cursor is located on line 8, column 66, entering `IE` from the keyboard will result in a display of "Ag" at the bottom right hand corner of the screen. This can save time in looking up the ASCII equivalent codes of the X, Y cursor coordinates to be used in cursor addressing. (Note that, `IE = ENQ = 05H.`)

The following is an example of how this could be used in a BASIC program.

```
PRINT CHR$( &H7E) + CHR$( &H11) + "Ag"
```

Upon execution of the above statement, the cursor will move to line 8, column 66.

Menu Display: In the local mode the user has access to a menu display that summarizes the terminal's functions, along with the corresponding control codes (see *Figure 1*). This feature is optional and resides in EPROM #2. The important thing to note is that various kinds of menu/HELP displays can be implemented easily in this fashion. This function can be accessed from the keyboard. Alternately, a dedicated HELP key (that generates the `1D` code) can be used.

ACKNOWLEDGEMENTS

We would like to thank Barry Siegel for his invaluable guidance and support. Also we would like to thank Ron Christopherson for contributing so much of his time to this project.

MOVE		INSERT		CURSOR		SPECIAL FUNC	
Lf	0A/0A	Lf	InChr *1E/1E	↑Rt	CurEn *03/03	↑C	Row2 /10
Cr	0D/0D	Cr	InLine *1A/1A	↑Lf	CurDi *06/06	↑F	Bell 07/
Tab	09/09	Tab	LnRng *1DIP/		RdCur *11PP/		Scale /07
Up	*0C/0C	Up			RdCur *05/		FgFlw *1F/1F
Down	*0B/0B	Dw	DELETE				BgFlw *19/19
Left	08/08	Lf	SoChr *04/04	↑L	CONTROL		Grphc *02P/02
Right	1B/10	Rt	SoLine *13/13	↑De1	OLlcl /00	OL/L	DeGrp *1B/1B
RollUp	*01/01	rup	LnRng *1DSP/		BdULc /7E	↑0/L	GrMan /11
RollDv	*16/16	TDW	DRstL *0F/0F	↑0	HxPge *0E/0E	↑M	TxLine *14/14
Home	*12/12	↑Cr	DRstP *17/17	↑0	Leadn 7E/		
			AmClr *1C/1C	↑1	LkKb *15/15	↑U	*=7E (leadin)
			CFB *18/18	↑X	UIkKb *03/03	↑C	func ol/1cl key

FIGURE 1. Sample Menu Display

Character Generator Fonts

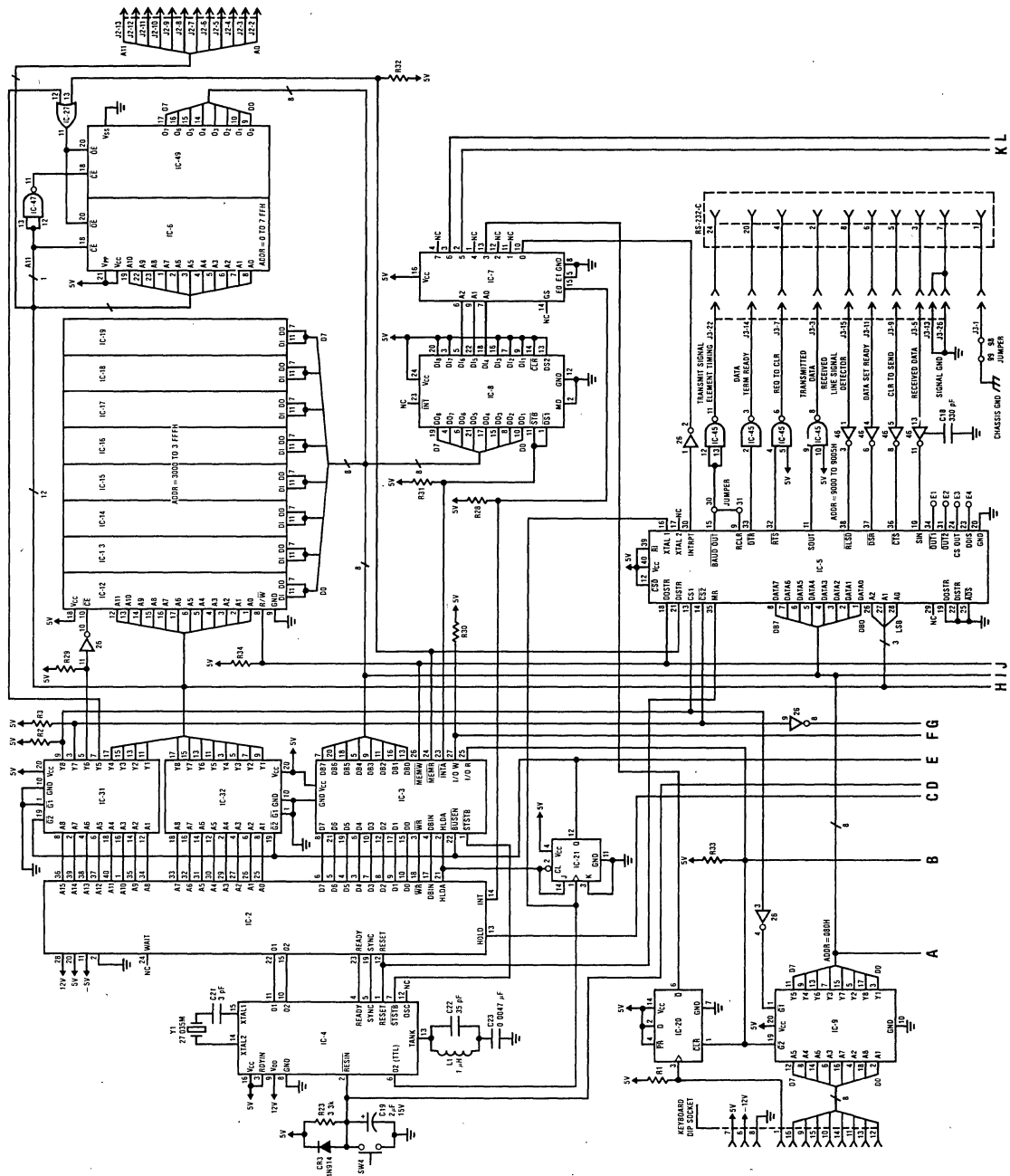
ADDR	00-0F	10-1F	20-2F	30-3F	40-4F	50-5F	60-6F	70-7F

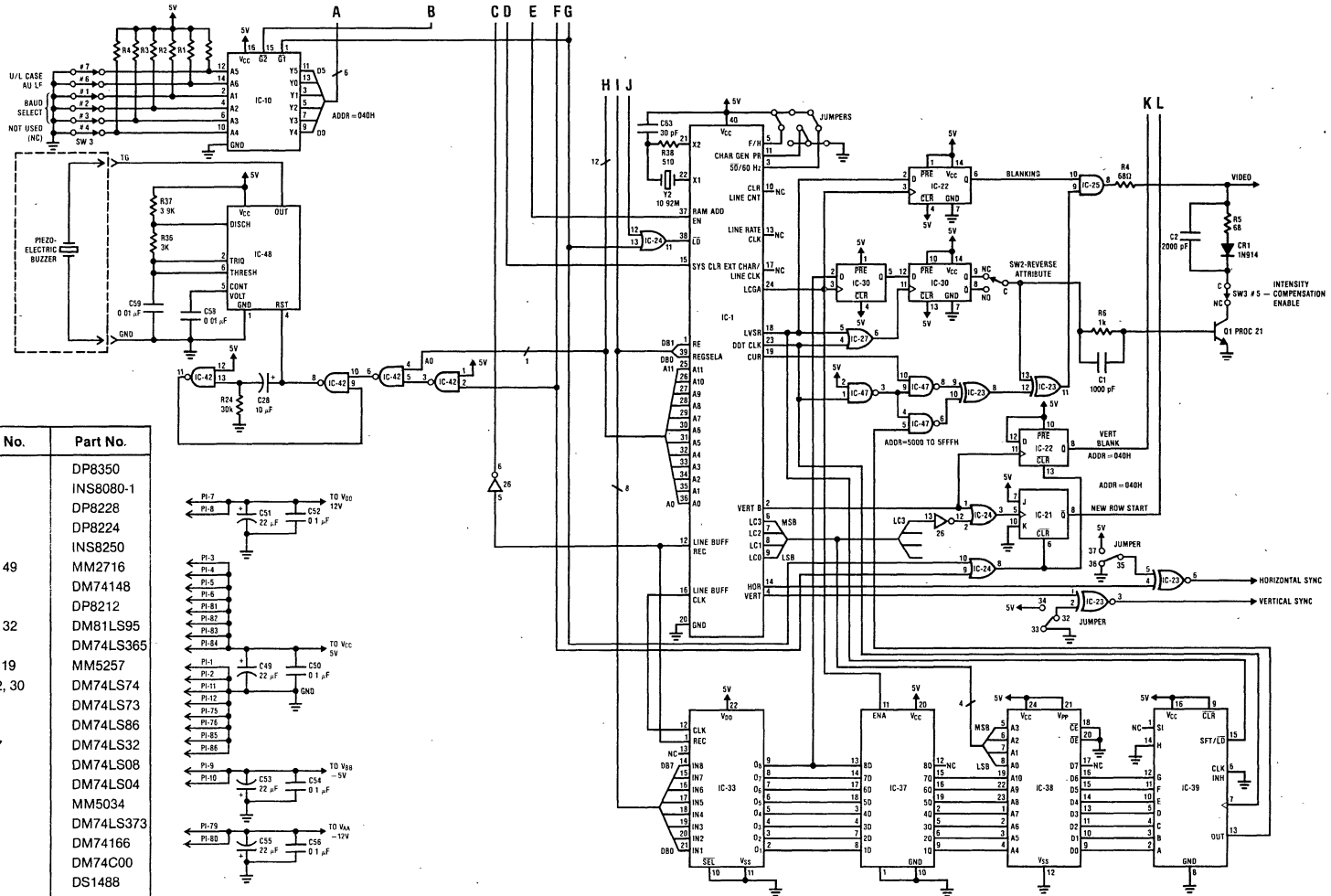
FIGURE 2. Sample Character Font

ABCDEFGHIJKLMNOPO	abcdefghijklmnopq

FIGURE 3. Graphics Menu Shown at the Bottom of the Screen

A complete listing of the software for the "High Speed Data Terminal" can be found on pages 5-84 through 5-103. A HEX dump of the character generator set is included on pages 5-82 and 5-83 and the schematic diagram on pages 5-79 and 5-80.





IC No.	Part No.
1	DP8350
2	INS8080-1
3	DP8228
4	DP8224
5	INS8250
6, 38, 49	MM2716
7	DM74148
8	DP8212
9, 31, 32	DM81LS95
10	DM74LS365
12 to 19	MM5257
20, 22, 30	DM74LS74
21	DM74LS73
23	DM74LS86
24, 27	DM74LS32
25	DM74LS08
26	DM74LS04
33	MM5034
37	DM74LS373
39	DM74166
42	DM74C00
45	DS1488
46	DS1489
47	DM74LS00
48	LM555

All pull-up resistors = 4.7k 1/4W

5-80

CONTROL FUNCTIONS SUMMARY

<u>Functions</u>	<u>On-Line / Local</u>	<u>Remarks</u>
Cursor Move/Control		
Line feed	0A / 0A	
Carriage return	0D / 0D	
Tab	09 / 09	
Cursor up	7E, 0C / 0C	
Cursor down	7E, 0B / 0B	
Cursor left	08 / 08	
Cursor right	10 / 10	
Home	7E, 12 / 12	
Home and clear	7E, 1C / 1C	
Enable cursor	7E, 03 / 03	
Disable cursor	7E, 06 / 06	
Address cursor	7E, 11, X, Y /	Remote only
Read cursor	7E, 05 / 05	
Insert		
Character insert	7E, 1E / 1E	
Line insert	7E, 1A / 1A	
Line insert with range	7E, 1D, 49, Y	Remote only
Delete		
Character strip	7E, 04 / 04	
Character delete	7F / 7F	
Line delete	7E, 13 / 13	
Line delete with range	7E, 1D, 53, Y /	Remote only
Clear to end of line	7E, 0F / 0F	
Clear to end of page	7E, 17 / 17	
Miscellaneous		
Local/remote	/ 00	Local only
Upper/lower case	/ 7E	Local only
Next page	7E, 0E / 0E	
Keyboard lock	7E, 15 / 15	
Keyboard unlock	7E, 03 / 03	
Bell	07 /	Remote only
Special Functions		
Function menu	/ 1D	A summary of available functions and their corresponding codes (local mode only).
Graphics on	7E, 02 / 02	Enter graphics mode.
Graphics off	7E, 1B / 1B	Exit graphics mode.
Graphics menu	/ 11	Line 23 displays upper and lower case characters and line 24 the corresponding graphics symbols (local).
Line transmit	7E, 14 / 14	Transmits the cursor line and inverts its attributes.
Foreground follows	7E, 1F / 1F	
Background follows	7E, 19 / 19	
Clear foreground	7E, 18 / 18	
Scale	/ 07	The line above the cursor becomes a scale (1-80). This is an aid for graphics and text alignment (local).
Roll up	7E, 01 / 01	
Roll down	7E, 16 / 16	

CHARACTER GENERATOR HEX DUMP

ADDR	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
0	14	14	14	14	14	14	14	14	14	14	0	0	0	0	0	0
10	0	0	0	7C	7C	7C	1C	1C	1C	1C	0	0	0	0	0	0
20	1C	1C	1C	1C	1C	1C	1C	1C	1C	1C	0	0	0	0	0	0
30	14	B	14	B	14	B	14	B	14	B	0	0	0	0	0	0
40	0	0	0	55	2A	55	0	0	0	0	0	0	0	0	0	0
50	0	0	0	7F	7F	7F	0	0	0	0	0	0	0	0	C	0
60	1C	1C	1C	7C	7C	7C	0	0	0	0	0	0	0	0	0	0
70	1C	1C	1C	1F	1F	1F	0	0	0	0	0	0	0	0	0	0
80	1C	1C	1C	7F	7F	7F	0	0	0	0	0	0	0	0	0	0
90	1C	1C	1C	7C	7C	7C	1C	1C	1C	1C	0	0	0	0	0	0
A0	1C	1C	1C	1F	1F	1F	1C	1C	1C	1C	0	0	0	0	0	0
B0	1C	1C	1C	7F	7F	7F	1C	1C	1C	1C	0	0	0	0	0	0
C0	0	0	0	7F	7F	7F	1C	1C	1C	1C	0	0	0	0	0	0
D0	0	0	0	1F	1F	1F	1C	1C	1C	1C	0	0	0	0	0	0
E0	1	3	7	E	C	18	38	70	60	40	0	0	0	0	0	0
F0	40	60	70	38	18	C	E	7	3	1	0	0	0	0	0	0

ADDR	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
100	0	0	B	1C	1C	3E	3E	3E	0	0	0	0	0	0	0	0
110	0	0	0	0	7B	B	B	B	B	B	0	0	0	0	0	0
120	B	B	B	B	B	B	B	B	B	B	0	0	0	0	0	0
130	0	0	3E	22	22	22	22	3E	0	0	0	0	0	0	0	0
140	0	0	B	1C	3E	1C	B	0	0	0	0	0	0	0	0	0
150	0	0	0	0	7F	0	0	0	0	0	0	0	0	0	0	0
160	B	B	B	B	7B	0	0	0	0	0	0	0	0	0	0	0
170	B	B	B	B	F	0	0	0	0	0	0	0	0	0	0	0
180	B	B	B	B	7F	0	0	0	0	0	0	0	0	0	0	0
190	B	B	B	B	7B	B	B	B	B	B	0	0	0	0	0	0
1A0	B	B	B	B	F	B	B	B	B	B	0	0	0	0	0	0
1B0	B	B	B	B	7F	B	B	B	B	B	0	0	0	0	0	0
1C0	0	0	0	0	7F	B	B	B	B	B	0	0	0	0	0	0
1D0	0	0	0	0	F	B	B	B	B	B	0	0	0	0	0	0
1E0	1	2	2	4	B	B	10	20	20	40	0	0	0	0	0	0
1F0	40	20	20	10	B	B	4	2	2	1	0	0	0	0	0	0

ADDR	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
200	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
210	0	B	B	B	B	B	0	B	0	0	0	0	0	0	0	0
220	A	A	14	0	0	0	0	0	0	0	0	0	0	0	0	0
230	0	0	14	3E	14	3E	14	0	0	0	0	0	0	0	0	0
240	0	B	1E	2E	1C	A	3C	B	0	0	0	0	0	0	0	0
250	0	32	32	4	B	10	26	26	0	0	0	0	0	0	0	0
260	0	B	14	14	18	2A	24	1A	0	0	0	0	0	0	0	0
270	B	B	10	0	0	0	0	0	0	0	0	0	0	0	0	0
280	0	B	10	20	20	20	10	B	0	0	0	0	0	0	0	0
290	0	B	4	2	2	2	4	B	0	0	0	0	0	0	0	0
2A0	0	B	2A	1C	2A	B	0	0	0	0	0	0	0	0	0	0
2B0	0	0	B	B	3E	B	B	0	0	0	0	0	0	0	0	0
2C0	0	0	0	0	0	0	0	B	10	0	0	0	0	0	0	0
2D0	0	0	0	0	3E	0	0	0	0	0	0	0	0	0	0	0
2E0	0	0	0	0	0	0	0	B	0	0	0	0	0	0	0	0
2F0	0	2	2	4	B	10	20	20	0	0	0	0	0	0	0	0

ADDR	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
300	0	1C	22	26	2A	32	22	1C	0	0	0	0	0	0	0	0
310	0	B	18	B	B	B	B	3E	0	0	0	0	0	0	0	0
320	0	1C	22	2	C	10	20	3E	0	0	0	0	0	0	0	0
330	0	3E	2	4	C	2	22	1C	0	0	0	0	0	0	0	0
340	0	4	C	14	24	3E	4	4	0	0	0	0	0	0	0	0
350	0	3E	20	3C	2	2	22	1C	0	0	0	0	0	0	0	0
360	0	1C	22	20	3C	22	22	1C	0	0	0	0	0	0	0	0
370	0	3E	22	2	4	B	B	B	0	0	0	0	0	0	0	0
380	0	1C	22	22	1C	22	22	1C	0	0	0	0	0	0	0	0
390	0	1C	22	22	1E	2	2	1C	0	0	0	0	0	0	0	0
3A0	0	0	0	B	0	0	B	0	0	0	0	0	0	0	0	0
3B0	0	0	0	B	0	0	B	10	0	0	0	0	0	0	0	0
3C0	0	4	B	10	20	10	B	4	0	0	0	0	0	0	0	0
3D0	0	0	0	3E	0	3E	0	0	0	0	0	0	0	0	0	0
3E0	0	10	B	4	2	4	B	10	0	0	0	0	0	0	0	0
3F0	0	1C	22	2	4	B	0	B	0	0	0	0	0	0	0	0

CHARACTER GENERATOR HEX DUMP (Continued)

ADDR	0	1	2	3	4	5	6	7	B	9	A	B	C	D	E	F
400	0	1C	22	2E	2A	2E	20	1E	0	0	0	0	0	0	0	0
410	0	1C	22	22	3E	22	22	22	0	0	0	0	0	0	0	0
420	0	3C	22	22	3C	22	22	3C	0	0	0	0	0	0	0	0
430	0	1C	22	20	20	20	22	1C	0	0	0	0	0	0	0	0
440	0	3C	22	22	22	22	22	3C	0	0	0	0	0	0	0	0
450	0	3E	20	20	3C	20	20	3E	0	0	0	0	0	0	0	0
460	0	3E	20	20	3C	20	20	20	0	0	0	0	0	0	0	0
470	0	1C	22	20	20	2E	22	1E	0	0	0	0	0	0	0	0
480	0	22	22	22	3E	22	22	22	0	0	0	0	0	0	0	0
490	0	1C	8	8	8	8	8	1C	0	0	0	0	0	0	0	0
4A0	0	1E	4	4	4	4	24	18	0	0	0	0	0	0	0	0
4B0	0	22	24	28	30	28	24	22	0	0	0	0	0	0	0	0
4C0	0	20	20	20	20	20	20	3E	0	0	0	0	0	0	0	0
4DC	0	22	36	2A	2A	22	22	22	0	0	0	0	0	0	0	0
4E0	0	22	22	32	2A	26	22	22	0	0	0	0	0	0	0	0
4F0	0	1C	22	22	22	22	22	1C	0	0	0	0	0	0	0	0

ADDR	0	1	2	3	4	5	6	7	B	9	A	B	C	D	E	F
500	0	3C	22	22	3C	20	20	20	0	0	0	0	0	0	0	0
510	0	1C	22	22	22	2A	24	1A	0	0	0	0	0	0	0	0
520	0	3C	22	22	3C	28	24	22	0	0	0	0	0	0	0	0
530	0	1C	22	20	1C	2	22	1C	0	0	0	0	0	0	0	0
540	0	3E	8	8	8	8	8	8	0	0	0	0	0	0	0	0
550	0	22	22	22	22	22	22	1C	0	0	0	0	0	0	0	0
560	0	22	22	22	14	14	8	8	0	0	0	0	0	0	0	0
570	0	22	22	22	2A	2A	2A	14	0	0	0	0	0	0	0	0
580	0	22	22	14	8	14	22	22	0	0	0	0	0	0	0	0
590	0	22	22	22	1C	8	8	8	0	0	0	0	0	0	0	0
5A0	0	3E	2	4	8	10	20	3E	0	0	0	0	0	0	0	0
5B0	0	E	8	8	8	8	8	E	0	0	0	0	0	0	0	0
5C0	0	20	20	10	8	4	2	2	0	0	0	0	0	0	0	0
5D0	0	3B	8	8	8	8	8	3B	0	0	0	0	0	0	0	0
5E0	0	8	1C	2A	8	8	8	8	0	0	0	0	0	0	0	0
5F0	0	0	8	10	3E	10	8	0	0	0	0	0	0	0	0	0

ADDR	0	1	2	3	4	5	6	7	B	9	A	B	C	D	E	F
600	10	8	4	0	0	0	0	0	0	0	0	0	0	0	0	0
610	0	0	0	1C	2	1E	22	1E	0	0	0	0	0	0	0	0
620	0	20	20	20	3C	22	22	3C	0	0	0	0	0	0	0	0
630	0	0	0	1E	20	20	20	1E	0	0	0	0	0	0	0	0
640	0	2	2	2	1E	22	22	1E	0	0	0	0	0	0	0	0
650	0	0	0	1C	22	3E	20	1C	0	0	0	0	0	0	0	0
660	0	4	8	8	1C	8	8	8	0	0	0	0	0	0	0	0
670	0	0	0	1E	22	22	1E	2	1C	0	0	0	0	0	0	0
680	0	20	20	20	3C	22	22	22	0	0	0	0	0	0	0	0
690	0	8	0	18	8	8	8	1C	0	0	0	0	0	0	0	0
6A0	0	4	0	4	4	4	24	18	0	0	0	0	0	0	0	0
6B0	0	10	10	12	14	18	14	12	0	0	0	0	0	0	0	0
6C0	0	18	8	8	8	8	8	1C	0	0	0	0	0	0	0	0
6D0	0	0	0	36	2A	2A	2A	2A	0	0	0	0	0	0	0	0
6E0	0	0	0	3C	22	22	22	22	0	0	0	0	0	0	0	0
6F0	0	0	0	1C	22	22	22	1C	0	0	0	0	0	0	0	0

ADDR	0	1	2	3	4	5	6	7	B	9	A	B	C	D	E	F
700	0	0	0	3C	22	22	3C	20	20	0	0	0	0	0	0	0
710	0	0	0	1E	22	22	1E	2	2	0	0	0	0	0	0	0
720	0	0	0	16	18	10	10	10	0	0	0	0	0	0	0	0
730	0	0	0	1E	20	1C	2	3C	0	0	0	0	0	0	0	0
740	0	8	8	1C	8	8	8	4	0	0	0	0	0	0	0	0
750	0	0	0	22	22	22	22	1C	0	0	0	0	0	0	0	0
760	0	0	0	22	22	22	14	8	0	0	0	0	0	0	0	0
770	0	0	0	22	22	2A	2A	14	0	0	0	0	0	0	0	0
780	0	0	0	22	14	8	14	22	0	0	0	0	0	0	0	0
790	0	0	0	22	22	22	1E	2	1C	0	0	0	0	0	0	0
7A0	0	0	0	3E	4	8	10	3E	0	0	0	0	0	0	0	0
7B0	6	8	8	10	20	10	8	8	6	0	0	0	0	0	0	0
7C0	0	8	8	8	0	8	8	8	0	0	0	0	0	0	0	0
7D0	30	8	8	4	2	4	8	8	30	0	0	0	0	0	0	0
7E0	0	0	0	7F	0	7F	0	0	0	0	0	0	0	0	0	0
7F0	0	1C	3E	36	22	22	36	3E	1C	0	0	0	0	0	0	0

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```

0000      ; May 1980
          ASEG
          ORG      00000h
          ; constants
000A      LF      equ      0Ah
000D      CR      equ      0Dh
0020      SPC      equ      020h
007E      LINC      equ      07Eh      ; leadin code
0060      RWRG      equ      low RR48-low RR1+2
0003      KULCDE      equ      03h      ; kbd unlock code
          ; I/O ports
0080      KBDPRT      equ      080h      ; keyboard
0040      ROWPRT      equ      040h      ; row interrupt
0040      VERPRT      equ      040h      ; vertical interrupt
0040      SETSW      equ      040h      ; baud sel, autolf, u/lcase
0002      LCLIND      equ      2      ; local indicator
0001      BELPRT      equ      1      ; bell
          ; ace
9000      ACEDTA      equ      09000h      ; data
9001      ACEITR      equ      ACEDTA+1; interrupt mask
9003      ACECTL      equ      ACEDTA+3; control
9005      ACESTU      equ      ACEDTA+5; transmit status
          ; ram assignment
3FFF      FROWH      equ      03FFFh      ; first row reg pair
3FFE      FROW      equ      FROWh-1
3FFD      LROWH      equ      FROWh-2      ; last row reg pair
3FFC      LROW      equ      FROWh-3
3FFB      CROWH      equ      FROWh-4      ; cursor row reg pair
3FFA      CROW      equ      FROWh-5
3FF9      CURH      equ      CROW-1      ; cursor reg pair
3FF8      CUR      equ      CROW-2
3FF7      TOPH      equ      CUR-1      ; top of page reg pair
3FF6      TOP      equ      CUR-2
3FF5      NRW      equ      TOP-1      ; row counter
3FF4      VCALEN      equ      TOP-2      ; vert calc routine enable
3FF3      GSYMBL      equ      VCALEN-1; graphics symbol
3FF2      AULF      equ      GSYMBL-1; auto linefeed, 0=auto lf
3FF1      LOCLM      equ      AULF-1      ; local mode, 0=remote
3FF0      ULCASE      equ      AULF-2      ; upper/lower case, 0=lower
3FEF      GECNTL      equ      AULF-3      ; graphic enable, 0=disable
3FEE      KBDLCK      equ      AULF-4      ; keyboard lock, 0=unlock
3FED      RTECTL      equ      KBDLCK-1; cursor blink rate cntl
3FEC      CUREN      equ      KBDLCK-2; cursor enable, 0=off
3FEB      CURTMR      equ      KBDLCK-3; cursor blinking timer
3FEA      FFNCT      equ      KBDLCK-4; ace fifo word count
3FE9      LEADIN      equ      KBDLCK-5; leadin mode, 0=no leadin
          ;
3FEB      ICMD      equ      KBDLCK-6; insert char mode, 0=insert
3FE7      CPYCTL      equ      ICMD-1      ; row copy direction cntl
3FE6      FFWR      equ      CPYCTL-1; fifo write pointer
3FE5      FFRD      equ      CPYCTL-2; fifo read pointer
3FE5      STK      equ      FFRD      ; stack      3FE4h down
3FA3      LINP      equ      FFEND+4      ; leadin parameter storage
3FA2      LINWCT      equ      FFEND+3      ; leadin word count

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3FA1      LINFH      equ      FFEND+2      ; leadin func jmp addr high
3FA0      LINF      equ      FFEND+1      ; leadin func jmp addr low
3F9F      FFEND      equ      03F9Fh      ; ace fifo end
3F50      FFSTR      equ      03F50h      ; ace fifo start 3F50/3F9Fh
3F20      FBG      equ      03F20h      ; fore/background cntl
3F00      DMYROW      equ      03F00h      ; dummy row 3F00/3F4Fh
3780      FCHR2      equ      03780h      ; page 2, 1st char

```

; INTERRUPTS

;*****

```

0000      F3      START:  DI      ; restart 0
0001      21 3F00      LXI      H, DMYROW      ; clr non video ram
0004      F9      SPHL
0005      C3 00E2      JMP      INIT
          -----

```

; row interrupt

```

0008      F5      ROW:   PUSH      PSW      ; restart 1
0009      0C      INR      C
000A      C2 0066      JNZ      NOWRAP      ; no wrap around
000D      C3 0061      JMP      VRRAP      ; do wrap around
          -----

```

; vertical interrupt

```

0010      E5      VERT:  PUSH      H      ; restart 2
0011      21 3FF5      LXI      H, NRW
0014      4E      MOV      C, M      ; load NRW
0015      C3 07AE      JMP      VTSUB
          -----

```

```

;ace duplicate interrupt
001B C3 003B ACEDUP: JMP ACE ;restart 3
;{FUNCTION} disable cursor
001B 21 3FEC DICUR: LXI H,CUREN ;disable cursor
001E 77 MOV M,A ;a=0
001F C9 RET

;-----
;keyboard interrupt
0020 E5 KBD: PUSH H ;restart 4
0021 F5 PUSH PSW
0022 21 3FEE LXI H,KBDLCK ;keyboard lock cntl
0025 C3 02C9 JMP KBDINT

;-----
;row duplicate interrupt
0028 F5 ROWDP: PUSH PSW ;restart 5
0029 0C INR C
002A C2 0066 JNZ NOWRAP
002D C3 0061 JMP VRWRAP

;-----
;vertical duplicate interrupt
0030 C3 0010 VERTDP: JMP VERT ;restart 6
0033 EB TABSTP: XCHG ;hl=crow
0034 D1 POP D ;remove call
0035 D1 POP D
0036 73 MOV M,E ;return org crow
0037 C9 RET

```

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003B

```

;ACE INTERRUPT
;*****
003B E5 ACE: PUSH H
0039 F5 PUSH PSW
003A 21 3FEB LXI H,CURTMR
003D D5 PUSH D
003E AF XRA A
003F 77 MOV M,A ;reset cursor timer
0040 2B DCX H ;FFWCT
0041 34 INR M ;fifo empty?
0042 C2 0244 JNZ STFIFD ;no, store to fifo

0045 2B DCX H ;leadin
0046 B6 ORA M
0047 3A 9000 LDA ACEDTA ;read ace
004A FB EI
004B C2 0283 JNZ LINMDE ;leadin mode

004E E6 7F FIFACE: ANI 07Fh
0050 11 0267 LXI D,FFCHK
0053 D5 PUSH D ;pseudo call
0054 FE 0A CPI LF
0056 CA 03B1 JZ LFEEED
0059 CD 015C CALL CALJMP
005C E6 B7 ANI 087h ;leadin+jmp addr high
005E FB RM ;leadin required, return
005F 67 LCLFUN: MOV H,A ;jmp addr high
0060 E9 PCHL ;do function

;row interrupt continue
;*****
0061 3E 01 VRWRAP: MVI A,1
0063 32 5000 STA 05000h ;wrap around addr
0066 D3 40 NOWRAP: OUT ROWPRT ;clr row flip/flop
0068 F1 POP PSW
0069 FB EI
006A C9 RET

;WRITE TO ACE
;*****
006B 3E 0D SNDCR: MVI A,CR
006D 57 WTACEA: MOV D,A

006E 3A 9005 WTACED: LDA ACESTU ;check status
0071 FE 60 CPI 060h ;hold/tx register
0073 DA 006E JC WTACED ;not ready
0076 CD 075E CALL $DLY ;delay

0079 7A OUTACE: MOV A,D
007A 32 9000 STA ACEDTA ;write to ace
007D C9 RET

```

PAGE

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;ROW START LOOKUP TABLE      (start addr=7Eh)
;*****
007E 3E80 ROW47D: dw 03E80h
0080 3000 ROW48D: dw 03000h
0082 3050 ROW1: dw 03050h
0084 30A0 ROW2: dw 030A0h
0086 30F0 ROW3: dw 030F0h
0088 3140 ROW4: dw 03140h
008A 3190 ROW5: dw 03190h
008C 31E0 ROW6: dw 031E0h
008E 3230 ROW7: dw 03230h
0090 3280 ROW8: dw 03280h
0092 32D0 ROW9: dw 032D0h
0094 3320 ROW10: dw 03320h
0096 3370 ROW11: dw 03370h
0098 33C0 ROW12: dw 033C0h
009A 3410 ROW13: dw 03410h
009C 3460 ROW14: dw 03460h
009E 34B0 ROW15: dw 034B0h
00A0 3500 ROW16: dw 03500h
00A2 3550 ROW17: dw 03550h
00A4 35A0 ROW18: dw 035A0h
00A6 35F0 ROW19: dw 035F0h
00A8 3640 ROW20: dw 03640h
00AA 3690 ROW21: dw 03690h
00AC 36E0 ROW22: dw 036E0h
00AE 3730 ROW23: dw 03730h
00B0 3780 ROW24: dw 03780h
00B2 37D0 ROW25: dw 037D0h
00B4 3820 ROW26: dw 03820h
00B6 3870 ROW27: dw 03870h
00B8 38C0 ROW28: dw 038C0h
00BA 3910 ROW29: dw 03910h
00BC 3960 ROW30: dw 03960h
00BE 39B0 ROW31: dw 039B0h
00C0 3A00 ROW32: dw 03A00h
00C2 3A50 ROW33: dw 03A50h
00C4 3AA0 ROW34: dw 03AA0h
00C6 3AF0 ROW35: dw 03AF0h
00C8 3B40 ROW36: dw 03B40h
00CA 3B90 ROW37: dw 03B90h
00CC 3BE0 ROW38: dw 03BE0h
00CE 3C30 ROW39: dw 03C30h
00D0 3C80 ROW40: dw 03C80h
00D2 3CD0 ROW41: dw 03CD0h
00D4 3D20 ROW42: dw 03D20h
00D6 3D70 ROW43: dw 03D70h
00D8 3DC0 ROW44: dw 03DC0h
00DA 3E10 ROW45: dw 03E10h
00DC 3E60 ROW46: dw 03E60h
00DE 3EB0 ROW47: dw 03EB0h
00E0 3F00 ROW48: dw 03F00h
PAGE

```

```

;INITIALIZE
;*****
00E2 3E 20 INIT: MVI A,SPC ;space
00E4 16 E9 MVI D,low LEADIN;byte count
00E6 CD 04C7 CALL DRLLP ;store spaces
00E9 AF XRA A
00EA 32 3FA2 STA LINWCT ;zero leadin word count
00ED 16 17 MVI D,256-low LEADIN;byte count
00EF CD 04C7 CALL DRLLP ;store zeros
00F2 31 3FE7 LXI SP,STK+2
00F5 21 5050 LXI H,05050h
00F8 E5 PUSH H ;set up fifo rd/wrt ptrs
00F9 CD 04AE CALL CURULK ;enable cursor,unlock kbd
00FC 32 3FEA STA FFWCT ;zero fifo word count(FFh)
00FF 23 INX H ;RTECTL
0100 36 1C MVI M,01Ch ;cursor blink cnt1
0102 2E FC MVI L,low LR0W;last row
0104 36 80 MVI M,low RR24
0106 2E FE MVI L,low FR0W;first row
0108 36 82 MVI M,low RR1
010A DB 80 IN KBDPRT ;clear keyboard intr
010C CD 04CE CALL CLRSCN ;clear screen
010F CD 07BF CALL ACESW ;init ace, read setsw
0112 3E 3F PATTN: MVI A,03Fh
0114 21 3780 LXI H,FCHR2 ;1st byte of page 2
0117 75 PTNLP: MOV M,L ;write pattern
0118 23 INX H
0119 BC CMP H

```

```

011A C2 0117      JNZ   PTNLP
011D D3 01        OUT   BELPRT ;ring bell for ready

;CALCULATE SCREEN ADDR AFTER VERTICAL INTERRUPT
011F 2E EB      VCAL: MVI   L,low CURTMR
0121 7E         MOV   A,M
0122 2F         CMA
0123 34         INR   M ;cursor timer
0124 23         INX   H ;cursor enable
0125 A6         ANA   M
0126 23         INX   H ;rate cnt1
0127 A6         ANA   M ;blink rate mask
0128 C4 0174    CNZ   CURLOC ;cursor on
012B 3E 20     MVI   A,020h ;B350 offset
012D 84         ADD   H ;offset addr high
012E 67         MOV   H,A ;=5Fh if cursor off
012F E5         PUSH  H ;save cursor
0130 2A 3FFE    LHLD  FRDW
0133 2B         DCX   H ;fetch row start
0134 7E         MOV   A,M
0135 C6 20     ADI   020h ;offset addr high
0137 57         MOV   D,A
0138 2B         DCX   H

```

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```

0139          MOV   E,M ;e=top of page
013A 5E         MOV   A,L ;calc row wrap constant
013B 7D         RRC   ;divide by 2
013C 0F         RRC   ;add offset
013C C6 8F     ADI   08Fh
013E E1         POP   H ;cursor location
013F F3         DI
0140 22 3FFB    SHLD  CUR ;update cursor
0143 EB         XCHG
0144 22 3FF6    SHLD  TOP ;update top of page
0147 21 3FF5    LXI   H,NRW
014A 77         MOV   M,A ;row wrap constant
014B 2B         DCX   H ;VCALEN
014C 36 00     MVI   M,0 ;disable VCAL routine
014E FB        WAIT: EI
014F 76         HLT
0150 7E         MOV   A,M ;VCALEN
0151 B7         ORA   A ;check from vert intr
0152 CA 014E   JZ    WAIT ;no
0155 C3 011F   JMP   VCAL ;do screen calculations

```

```

;CALCULATE JMP ADDR
0158 2E E9     CJMP: MVI   L,low LEADIN
015A E6 7F     ANI   07Fh ;mask 1st bit
015C FE 20     CALJMP: CPI  SPC
015E DA 0168   JC    FUNC ;0-1Fh, func
0161 FE 7E     CPI   07Eh
0163 DA 0372   JC    CHAR ;20-7Dh, char input
0166 D6 5E     SUI   05Eh ;7E/7Fh to 20/21h
0168 2B         DCX   H ;insert mode
0169 74         MOV   M,H ;h<>0, defeat insert mode
016A 07         JMPADD: RLC ;*2, msb=0
016B 5F         MOV   E,A ;d=02h (jmp tbl)
016C 1A         LDAX  D ;fetch jmp addr low
016D 6F         MOV   L,A
016E 13         INX   D
016F 1A         LDAX  D ;fetch jmp addr high
0170 C9         RET

```

```

;CALCULATE CUR LOC AND CUR TO END DIFF
0171 3E 50     DFCLC: MVI  A,80
0173 90         SUB   B ;cursor to end difference

```

```

;CALCULATE CURSOR LOCATION
0174 2A 3FFA    CURLOC: LHLD  CROW
0177 2B         DCX   H
0178 56         MOV   D,M
0179 2B         DCX   H
017A 5E         MOV   E,M
017B 68         MOV   L,B
017C 19         DAD   D ;h1=cursor address
017D C9         RET

```

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```

017E          ;ROW WRAP AROUND LOOKUP TABLE (start addr=17Eh)
;*****
017E 00E0      RR47D: dw  00E0h
0180 0082      RR48D: dw  0082h
0182 0084      RR1:  dw  0084h

```

0184	0086	RR2:	dw	0086h
0186	0088	RR3:	dw	0088h
0188	008A	RR4:	dw	008Ah
018A	008C	RR5:	dw	008Ch
018C	008E	RR6:	dw	008Eh
018E	0090	RR7:	dw	0090h
0190	0092	RR8:	dw	0092h
0192	0094	RR9:	dw	0094h
0194	0096	RR10:	dw	0096h
0196	0098	RR11:	dw	0098h
0198	009A	RR12:	dw	009Ah
019A	009C	RR13:	dw	009Ch
019C	009E	RR14:	dw	009Eh
019E	00A0	RR15:	dw	00A0h
01A0	00A2	RR16:	dw	00A2h
01A2	00A4	RR17:	dw	00A4h
01A4	00A6	RR18:	dw	00A6h
01A6	00A8	RR19:	dw	00A8h
01A8	00AA	RR20:	dw	00AAh
01AA	00AC	RR21:	dw	00ACh
01AC	00AE	RR22:	dw	00AEh
01AE	00B0	RR23:	dw	00B0h
01B0	00B2	RR24:	dw	00B2h
01B2	00B4	RR25:	dw	00B4h
01B4	00B6	RR26:	dw	00B6h
01B6	00B8	RR27:	dw	00B8h
01B8	00BA	RR28:	dw	00BAh
01BA	00BC	RR29:	dw	00BCh
01BC	00BE	RR30:	dw	00BEh
01BE	00C0	RR31:	dw	00C0h
01C0	00C2	RR32:	dw	00C2h
01C2	00C4	RR33:	dw	00C4h
01C4	00C6	RR34:	dw	00C6h
01C6	00C8	RR35:	dw	00C8h
01C8	00CA	RR36:	dw	00CAh
01CA	00CC	RR37:	dw	00CCh
01CC	00CE	RR38:	dw	00CEh
01CE	00D0	RR39:	dw	00D0h
01D0	00D2	RR40:	dw	00D2h
01D2	00D4	RR41:	dw	00D4h
01D4	00D6	RR42:	dw	00D6h
01D6	00D8	RR43:	dw	00D8h
01D8	00DA	RR44:	dw	00DAh
01DA	00DC	RR45:	dw	00DCh
01DC	00DE	RR46:	dw	00DEh
01DE	00E0	RR47:	dw	00E0h
01E0	00E2	RR48:	dw	00E2h
01E2	00E4	RR1D:	dw	00E4h

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```

; JUMP ADDRESS CONSTANTS
; *****
; A15      :- 0=no leadin required
; A14/A12 :- parameter count
; A11     :- 0=local function
1000      W1      equ      01000h ;one para adder
2000      W2      equ      02000h ;two para adder
8000      LIN     equ      08000h ;leadin adder
0800      NLC     equ      00800h ;not local adder

0A5F      F1      equ      RTN+NLC
03B9      F2      equ      CARRTN
03B1      F3      equ      LFEEED
0C34      F4      equ      BELL+NLC
060A      F5      equ      TAB
0437      F6      equ      FS
041F      F7      equ      BS

844E      F8      equ      UPCUR+LIN
8460      F9      equ      DWNCUR+LIN
84DB      F10     equ      HOMCUR+LIN
85F3      F11     equ      NPAGE+LIN
8472      F12     equ      ROLUP+LIN
848C      F13     equ      ROLDWN+LIN

84AE      F14     equ      CURULK+LIN
8DD1      F15     equ      RDCUR+LIN+NLC
ADA2      F16     equ      ADDCUR+LIN+NLC+W2

84F1      F17     equ      FGND+LIN
84F7      F18     equ      BGND+LIN

836B      F19     equ      INSCHAR+LIN
8358      F20     equ      STOFCH+LIN
8505      F21     equ      INSLNE+LIN
8512      F22     equ      STOFLE+LIN
AD26      F23     equ      ISLRG+LIN+NLC+W2
9E8A      F24     equ      GRAPH+LIN+NLC+W1

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0419	F25	equ	DEL
83DB	F26	equ	DCROW+LIN
84C0	F27	equ	DRTLN+LIN
84BA	F28	equ	DRTPG+LIN
8642	F29	equ	CFB+LIN
84CE	F30	equ	CLRSCN+LIN
8CB6	F31	equ	KBLK+LIN+NLC
801B	F32	equ	DICUR+LIN
871D	F33	equ	SNDLNE+LIN
87BF	F34	equ	ACESW+LIN
0AC5	F35	equ	LINSET+NLC
86BC	F36	equ	DEGRPH+LIN
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CRT801
01E4
; PUT A WORD TO ACE
01E4 57          KBDACE: MDV   D,A
01E5 3A 9005    LDA   ACESTU
01EB E6 20      ANI   020h
01EA CA 01E5    JZ    KBDACE+1;not ready
01ED C3 0079    JMP   OUTACE

; ACE BAUD RATE CONSTANTS
01F0 06AB      B110:  dw   1707      ; 0
01F2 0139      B600:  dw   313       ; 1
01F4 009C      B1200: dw   156      ; 0.3% 2
01F6 004E      B2400: dw   78       ; 0.3% 3
01FB 0027      B4800: dw   39       ; 0.3% 4
01FA 0014      B9600: dw   20       ; 2.3% 5
01FC 000A      B19200: dw  10       ; 2.3% 6
01FE 0005      B38400: dw   5       ; 2.3% 7

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```

; FUNCTION JUMP TABLE (start addr=200h)
; *****
0200 0A5F      TBLJMP: dw   F1       ; null/toggle local
0202 8472      dw   F12      ; A: roll up
0204 9E8A      CB:   dw   F24      ; B: graphics mode
0206 84AE      dw   F14      ; C: on cursor/unlock kbd
0208 8358      dw   F20      ; D: strip off character
020A BDD1      CE:   dw   F15      ; E: read cursor
020C 801B      dw   F32      ; F: disable cursor
020E 0C34      CG:   dw   F4       ; G: bell/scale
0210 041F      dw   F7       ; H: cursor left
0212 060A      dw   F5       ; I: tab
0214 03B1      dw   F3       ; J: line feed
0216 8460      dw   F9       ; K: cursor down
0218 844E      dw   F8       ; L: cursor up
021A 03B9      dw   F2       ; M: carriage return
021C 89F3      dw   F11      ; N: next page
021E 84C0      dw   F27      ; O: delete rest of line
0220 0437      dw   F6       ; P: cursor right
0222 ADA2      CG:   dw   F16      ; Q: address cursor/menu
0224 84DB      dw   F10      ; R: home cursor
0226 8512      dw   F22      ; S: strip off a line
0228 871D      dw   F33      ; T: transmit a line
022A 8CB6      CU:   dw   F31      ; U: lock keyboard
022C 84BC      dw   F13      ; V: roll down
022E 84BA      dw   F28      ; W: delete rest of page
0230 8442      dw   F29      ; X: clear fore/background
0232 84F7      dw   F18      ; Y: background follows
0234 8505      dw   F21      ; Z: insert line
0236 86BC      dw   F36      ; 1B: esc/defeat graphics
0238 84CE      dw   F30      ; 1C: home and clear screen
023A AD26      C1D:  dw   F23      ; 1D: insert/strip line/rng
023C 836B      dw   F19      ; 1E: insert character
023E 84F1      dw   F17      ; 1F: foreground follows
0240 0AC5      C7E:  dw   F35      ; 7E: leadin/ace,u/l-case
0242 0419      dw   F25      ; 7F: delete

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CRT801
; STORE A WORD TO ACE FIFO
0244 3E 50      STFIFO: MVI   A,80
0246 BE        CMP   M ;exceeding 80 words?
0247 3A 9000    LDA   ACEDTA ;read ace
024A DA 032C    JC    OVRNG ;more than 80 words
024D 2E E6      MVI   L,low FFWR
024F 54        MOV   D,H ;set up write pointer high
0250 5E        MOV   E,M ;set up write pointer low
0251 12        STAX D ;store to fifo
0252 7B        MOV   A,E
0253 3C        INR  A ;advance pointer
0254 FE A0     CPI   low FFEND+1;exceeding 80 words?
0256 DA 025A   JC    WFFRNG ;less than 80 words
0259 1F        RAR  ;fifo start again

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025A 77      WFFRNG: MOV      M, A      ; advance write pointer
025B FB      EI

025C D1      CMRTN: POP      D
025D F1      POP      PSW
025E E1      POP      H

; (FUNCTION) unused keys
025F C9      RTN:      RET

; KEY BOARD RETURN, addr high=2h
0260 AF      KLCRTN: XRA     A      ; enable keyboard
0261 32 3FEE STA     KBDLCK
0264 C3 025C JMP     CMRTN

; CHECK FIFO AND RETURN, addr high=2h
0267 21 3FEA FFCHK: LXI     H, FFWCT ; fifo word count
026A 35      DCR     M      ; fifo empty?
026B FA 025C JM      CMRTN ; empty

; READ A WORD FROM ACE FIFO
026E 2E E5   RDFIFO: MVI     L, low FFRD
0270 54      MOV     D, H      ; set up read pointer high
0271 5E      MOV     E, M      ; set up read pointer low
0272 7B      MOV     A, E
0273 3C      INR     A      ; advance read pointer
0274 FE A0   CPI     low FFEND+1; exceeding 80 words?
0276 DA 027A JC     RFFRNG ; less than 80 words
0277 1F      RAR     ; fifo start again
027A 77      RFFRNG: MOV    M, A ; store read pointer
027B 2E E9   MVI     L, low LEADIN
027D 7E      MOV     A, M
027E B7      ORA     A      ; leadin mode=0?
027F 1A      LDAX   D      ; read fifo word
0280 CA 004E JZ     FIFACE ; not leadin, normal entry

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0283
; LEADIN MODE
0283 E6 7F   LINMDE: ANI     07Fh ; mask input
0285 11 0267 LXI     D, FFWCT
0288 D5      PUSH   D      ; pseudo call
0289 2E A2   MVI     L, low LINWCT
028B 5E      MOV     E, M      ; leadin word count
028C 1D      DCR     E      ; word count=0?
028D F2 02B3 JP     LINPRA ; parameter entries
0290 FE 20   CPI     SPC      ; control codes?
0292 D2 02C2 JNC    ILELIN ; not cntl code, error
0295 CD 016A CALL   JMPADD ; fetch jmp address
0298 B7      ORA     A
0299 F2 02C2 JP     ILELIN ; code requires no leadin
029C E6 77   ANI     077h ; word count/jmp addr high
029E 67      MOV     H, A      ; save
029F E6 70   ANI     070h ; mask word count
02A1 CA 02BE JZ     LINEXE ; do function

02A4 0F      LINPFN: RRC     ; right justify word count
02A5 0F      RRC
02A6 0F      RRC
02A7 0F      RRC
02A8 32 3FA2 STA   LINWCT ; store to word count reg
02AB 3E 07   MVI     A, 07h
02AD A4      ANA     H      ; get jmp addr high
02AE 67      MOV     H, A
02AF 22 3FA0 SHLD  LINF ; save function jmp addr
02B2 C9      RET

02B3 73      LINPRA: MOV    M, E ; leadin word count-1
02B4 16 00   MVI     D, 0 ; d=0, e=word count-1
02B6 23      INX     H      ; LINP
02B7 19      DAD     D      ; hl=para pointer
02B8 77      MOV     M, A ; store word
02B9 C0      RNZ     ; word count<>0, next word
02BA 2A 3FA0 LHLD  LINF ; load leadin jmp address
02BD AF      XRA     A

02BE 32 3FE9 LINEXE: STA   LEADIN ; defeat leadin
02C1 E9      PCHL ; do function

02C2 D3 01   ILELIN: OUT   BELPRT ; illegal code after leadin
02C4 AF      XRA     A ; a=0, reset leadin

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;{FUNCTION} set leadin mode
02C5 32 3FE9 LINSET: STA LEADIN ;a<0, set leadin
02C8 C9 RET

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02C9

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;keyboard interrupt continue
KBDINT: XRA A
02CA 32 3FEB STA CURTMR ;reset cursor blink timer
02CD B6 ORA M ;keyboard locked?
02CE DB 80 IN KBDPRT ;read keyboard
02D0 FB EI
02D1 D5 PUSH D
02D2 C2 0327 JNZ KNACTV ;keyboard not active

02D5 B7 ORA A
02D6 CA 0333 JZ TGLCL ;toggle local
;defeat graphics
02D9 77 MOV M,A ;lock keyboard
02DA 11 0260 LXI D,KLCRTN
02DD D5 PUSH D ;generate pseudo call

02DE 23 INX H ;GECNTL
02DF B6 ORA M
02E0 23 INX H ;ULCASE
02E1 FE 61 CPI 061h
02E3 DA 02EC JC NLCSE ;not lower case
02E6 FE 7B CPI 07Bh
02E8 D2 02EC JNC NLCSE ;not lower case
02EB 96 SUB M ;u/1 case cntl,m=20h/0

02EC 23 NLCSE: INX H ;local
02ED 5E MOV E,M
02EE 1C INR E ;local mode?
02EF C2 01E4 JNZ KBDACE ;write to ace

02F2 FE A0 LCL: CPI OAOH ;parameter entry?
02F4 D2 06BD JNC LGPARA ;yes

02F7 CD 015B CALL CJMP ;get jmp addr
02FA E6 0F ANI 0Fh
02FC FE 08 CPI 08h ;local?
02FE DA 005F JC LCLFUN ;do local function
0301 7B MOV A,E ;read lookup tbl ptr
0302 FE 05 CPI low CB+1;cntl B?
0304 CA 06B7 JZ ENGRPH ;enable graphics mode
0307 FE 08 CPI low CE+1;cntl E?
0309 CA 0773 JZ LRDCUR ;display cursor location
030C FE 0F CPI low CG+1;cntl G?
030E CA 07B4 JZ SCALE ;put scale
0311 FE 23 CPI low CG+1;cntl G?
0313 CA 06D5 JZ PGM ;put graphics menu
0316 FE 41 CPI low C7E+1
0318 CA 07CD JZ ATGUL ;init ace,toggle u/1 case
031B FE 3B CPI low C1D+1
031D CA 034F JZ ROM2 ;do rom2 functions
0320 FE 2B CPI low CU+1;cntl U?

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0322 C0 RNZ ;unused keys
0323 D1 POP D ;pseudo rtn+lock kbd
0324 C3 0261 JMP KLCRTN+1

0327 EE 03 KNACTV: XRI KULCDE ;lock/unlock kbd?
0329 CA 025A JZ CMRTN-2 ;unlock keyboard
032C 3E 50 OVRNG: MVI A,80 ;for FFWCT
032E D3 01 OUT BELPRT
0330 C3 025A JMP CMRTN-2 ;lock kbd

0333 23 TGLCL: INX H ;GECNTL
0334 77 MOV M,A ;disable graphics mode
0335 32 3FE9 STA LEADIN ;reset leadin
0338 2E F1 MVI L,low LOCLM
033A 7E MOV A,M
033B 2F CMA ;toggle local
033C 77 MOV M,A
033D CD 07E8 CALL EDACE ;en/disable ace
0340 C2 0345 JNZ ONLINE
0343 3E 1E MVI A,03h XOR 01Dh
0345 EE 1D ONLINE: XRI 01Dh

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0347 00          nop          ;out lclprt
0348 00          nop
0349 32 3FED    STA          RTECTL ;select blink rate
034C C3 025C    JMP          CMRTN

; JMP TO ROM2
034F 3A 0800    ROM2: LDA          0800h ;check presence of rom2
0352 FE 55     CPI          055h  ;=55h?
0354 C0       RNZ
0355 C3 0801    JMP          0801h ;ok, do jmp

; <FUNCTION> stripe off a character
0358 CD 0171    STDFCH: CALL DFCLDC ;get cur loc and diff
035B 3D       DCR          A
035C CA 0434    JZ          BELL    ;last column, error
035F 23       STDFLP: INX          H
0360 56       MOV          D,M
0361 2B       DCX          H
0362 72       MOV          M,D ;do copy
0363 23       INX          H
0364 3D       DCR          A
0365 C2 035F    JNZ        STDFLP
0368 C3 03A4    JMP          PSPC    ;put a space

; <FUNCTION> insert character
036B AF       INBCHAR: XRA         A
036C 32 3FEB    STA          ICMD    ;enable insert mode
036F C3 03BD    JMP          INBCHR

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0372          ; CHARACTER INPUT
0372 D1       CHAR: POP          D ;pseudo return
0373 2E 20    MVI          L,low FBG
0375 AE       XRA          M ;add attribute
0376 AD       XRA          L ;remove space code

0377 2A 3FFA    LHLD         CROW    ;calculate cursor loc
037A 2B       DCX          H
037B 56       MOV          D,M
037C 2B       DCX          H
037D 5E       MOV          E,M
037E 68       MOV          L,B ;row start+cursor
037F 19       DAD          D ;hl=cursor address
0380 77       MOV          M,A ;write to screen

0381 3E 4F     MVI          A,79
0383 AB       XRA          B ;last column?
0384 CA 03C0    JZ          LSTCHR ;last, do scroll
0387 04       MIDCHR: INR          B ;else advance cursor
0388 3A 3FEB    LDA          ICMD ;insert mode?
038B B7       ORA          A
038C C0       RNZ          ;not insert mode

038D 3E 4F     INBCHR: MVI         A,79
038F 90       SUB          B ;byte counter
0390 CA 03AB    JZ          ILCHAR ;cursor at last column

0393 2A 3FFA    LHLD         CROW
0396 5E       MOV          E,M
0397 23       INX          H
0398 56       MOV          D,M ;d=row end+1
0399 1B       DCX          D ;row end
039A EB       XCHG
039B 2B       INSLP: DCX         H
039C 56       MOV          D,M
039D 23       INX          H
039E 72       MOV          M,D ;do copy
039F 2B       DCX          H
03A0 3D       DCR          A
03A1 C2 039B    JNZ        INSLP

03A4 3E 80     PSPC: MVI          A,080h
03A6 A2       ANA          D ;get character attribute
03A7 F6 20    ORI          SPC ;add space
03A9 77       MOV          M,A
03AA C9       RET

03AB 3C       ILCHAR: INR         A ;make a<0
03AC D3 01    OUT          BELPRT
03AE C3 03CE    JMP          DICMD ;defeat insert char mode

PAGE

```

```

STARPLEX MACRO-ASSEMBLER V2.0          PAGE    15
CRT801
03B1
;{FUNCTION} line feed
03B1 3A 3FF2 LFEED: LDA AULF ;auto line feed?
03B4 B7      ORA  A
03B5 C2 03C1 JNZ  LFD  ;do line feed
03B8 C9      RET

;{FUNCTION} carriage return
03B9 3A 3FF2 CARRTN: LDA AULF ;auto line feed?
03BC B7      ORA  A
03BD C2 04DE JNZ  ZROCUR ;do cr only

03C0 47      LSTCHR: MOV  B,A  ;set cursor to 1st col

03C1 11 3FFC LFD:  LXI  D,LROW
03C4 2A 3FFA LHL  CRDW
03C7 24      INR  H
03C8 1A      LDAX D
03C9 BD      CMP  L ;crow=lrow?
03CA 7E      MOV  A,M ;next row
03CB 32 3FFA STA  CROW ;crow+1
03CE 32 3FEB DICMD: STA  ICMD ;defeat insert char mode
03D1 C0      RNZ  ;not last row

03D2 EB      LFSCR: XCHG ;last row, do scroll
03D3 F3      DI
03D4 77      MOV  M,A ;lrow+1
03D5 2E FE   MVI  L,low FROW
03D7 5E      MOV  E,M ;de=row wrap around tbl
03D8 1A      LDAX D
03D9 77      MOV  M,A ;frow+1
03DA FB      EI

;{FUNCTION} clear cursor row
03DB 2A 3FFA DCROW: LHL  CROW

03DE EB      CLRROW: XCHG
03DF 21 0000 LXI  H,0
03E2 39      DAD  SP
03E3 EB      XCHG
03E4 F3      DI
03E5 F9      SPHL
03E6 E1      POP  H ;lookup row start
03E7 F9      SPHL ;sp=row start
03E8 FB      EI
03E9 2A 3F20 LHL  FBQ ;space + attribute

PAGE

```

```

STARPLEX MACRO-ASSEMBLER V2.0          PAGE    16
CRT801
03EC
03EC E5      PUSHSP: PUSH H ;do clear row
03ED E5      PUSH H
03EE E5      PUSH H
03EF E5      PUSH H
03F0 E5      PUSH H
03F1 E5      PUSH H
03F2 E5      PUSH H
03F3 E5      PUSH H
03F4 E5      PUSH H
03F5 E5      PUSH H ;10
03F6 E5      PUSH H
03F7 E5      PUSH H
03F8 E5      PUSH H
03F9 E5      PUSH H
03FA E5      PUSH H
03FB E5      PUSH H
03FC E5      PUSH H
03FD E5      PUSH H
03FE E5      PUSH H
03FF E5      PUSH H ;20
0400 E5      PUSH H
0401 E5      PUSH H
0402 E5      PUSH H
0403 E5      PUSH H
0404 E5      PUSH H
0405 E5      PUSH H
0406 E5      PUSH H
0407 E5      PUSH H
0408 E5      PUSH H
0409 E5      PUSH H ;30
040A E5      PUSH H
040B E5      PUSH H
040C F3      DI

```

```

040D E5          PUSH H
040E E5          PUSH H
040F E5          PUSH H
0410 E5          PUSH H
0411 E5          PUSH H
0412 E5          PUSH H
0413 E5          PUSH H
0414 E5          PUSH H      ; 40
0415 EB          XCHG
0416 F9          SPHL
0417 FB          BSRTN: EI
0418 C9          RET

```

```

; <FUNCTION> delete
0419 3E 20      DEL: MVI A,SPC
041B CD 06CB   CALL STSP ; store space
041E AF        XRA A ; do back space

```

PAGE

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CRTBO1

041F

```

; <FUNCTION> back space
041F C4 06C1   BS: CNZ CHKGM ; check graphics mode
0422 F3        BS1: DI
0423 05        DCR B ; cursor-1
0424 F2 0417   JP BSRTN ; not 1st column
0427 04        INR B
0428 FB        EI
0429 3A 3FEF   LDA GECNTL
042C B7        ORA A ; graphics mode?
042D C0        RNZ ; defeat wrap around
042E CD 0451   CALL UCUR1 ; up cursor one row
0431 CB        RZ ; crow=frow?
0432 06 4F    MVI B,79 ; set cursor to last col
0434 D3 01    BELL: OUT BELPRT
0436 C9        RET

```

```

; <FUNCTION> forward cursor
0437 CD 06C1   FS: CALL CHKGM ; check graphics mode
043A 3E 4F    MVI A,79
043C BB        CMP B ; last column?
043D C2 03B7   JNZ MIDCHR ; not last column
0440 3A 3FEF   LDA GECNTL
0443 B7        ORA A ; graphics mode?
0444 C0        RNZ ; defeat wrap around
0445 CD 0463   CALL DCUR1 ; down cursor one row
0448 CB        RZ ; crow=lrow?
0449 06 00    MVI B,0 ; set cursor to 1st col
044B D3 01    OUT BELPRT
044D C9        RET

```

```

; <FUNCTION> up cursor one row
044E CD 06C1   UPCUR: CALL CHKGM ; check graphics mode
0451 11 3FFA   UCUR1: LXI D,CROW
0454 2A 3FFE   LHL D, FROW
0457 1A        LDAX D ; crow
0458 24        INR H ; hl=row wrap around tbl
0459 BD        CMP L ; crow=frow?
045A C2 04A7   JNZ $4
045D D3 01    OUT BELPRT ; crow=frow, ring bell
045F C9        RET

```

```

; <FUNCTION> down cursor one row
0460 CD 06C1   DWNCUR: CALL CHKGM ; check graphics mode
0463 11 3FFA   DCUR1: LXI D,CROW
0466 2A 3FFC   LHL D, LRW
0469 1A        LDAX D ; crow
046A 24        INR H ; hl=row wrap around tbl
046B BD        CMP L ; crow=lrow?
046C C2 04A9   JNZ $5
046F D3 01    OUT BELPRT ; crow=lrow, ring bell
0471 C9        RET

```

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CRTBO1

0472

```

; <FUNCTION> roll up
0472 11 3FFA   ROLUP: LXI D,CROW
0475 2A 3FFE   LHL D, FROW
0478 1A        LDAX D
0479 24        INR H ; hl=row wrap around tbl
047A BD        CMP L ; crow=frow?
047B 7E        MOV A,M ; next row
047C F3        DI
047D 32 3FFE   STA FROW ; frow+1
0480 C2 0484   JNZ RUNEG

```

```

0483 12          STAX      D          ;crow+1
0484 EB          RUNEQ:  XCHG     ;d=1,h=3Fh
0485 2E FC       MVI      L,low LROW
0487 5E         MOV      E,M      ;de=row wrap around tbl
0488 1A         LDAX     D          ;next row
0489 77         MOV      M,A      ;lrow+1
048A FB         EI
048B C9         RET

; {FUNCTION} roll down
048C 11 3FFA    ROLDWN: LXI     D,CROW
048F 3A 3FFC    LDA      LROW
0492 D6 04     SUI      4          ;up one row
0494 6F         MOV      L,A
0495 26 01     MVI      H,1      ;hl=row wrap around tbl
0497 1A         LDAX     D          ;crow
0498 D6 04     SUI      4
049A BD         CMP      L          ;crow=lrow?
049B 7E         MOV      A,M      ;up one row
049C F3         DI
049D 32 3FFC    STA      LROW      ;lrow-1
04A0 C2 04A4    JNZ     RDNEQ
04A3 12         STAX     D          ;crow-1
04A4 1E FE     RDNEQ: MVI     E,low FROW
04A6 1A         LDAX     D
04A7 D6 04     $4:    SUI      4
04A9 6F         $5:    MOV      L,A      ;hl=row wrap around tbl
04AA 7E         MOV      A,M
04AB 12         STAX     D          ;frow-1
04AC FB         EI
04AD C9         RET

; {FUNCTION} enable cursor, unlock keyboard
04AE AF         CURULK: XRA      A
04AF 32 3FEE    STA      KBDLCK ;unlock keyboard
04B2 2F         CMA
04B3 C3 001B    JMP     DICUR ;enable cursor

; {FUNCTION} lock keyboard
04B6 32 3FEE    KBLK:  STA      KBDLCK ;lock keyboard
04B7 C9         RET

PAGE

STARPLEX MACRO-ASSEMBLER V2.0          PAGE 19
CRT801
04BA          ; {FUNCTION} delete rest of page
04BA 3A 3FFA    DRTPG: LDA      CROW
04BD CD 04E9    CALL     CTRW2 ;clear crow+1 to lrow

; {FUNCTION} delete rest of line
04C0 CD 0171    DRTLN: CALL     DFCLC ;get cursor loc and diff
04C3 57         MOV      D,A      ;save
04C4 3A 3F20    LDA      FBG
04C7 77         DRLLP: MOV      M,A      ;store space/attribute
04C8 23         INX      H
04C9 15         DCR      D
04CA C2 04C7    JNZ     DRLLP ;until end of line
04CD C9         RET

; {FUNCTION} clear screen
04CE CD 06BC    CLRSCN: CALL     DEGRPH ;defeat graphics mode
04D1 2A 3FFE    LHL     FROW
04D4 7D         MOV      A,L
04D5 CD 04E6    CALL     CTRW1 ;clear frow to lrow

; {FUNCTION} home cursor
04DB 3A 3FFE    HOMCUR: LDA      FROW
04DB 32 3FFA    STA      CROW ;crow=frow
04DE 06 00     ZROCUR: MVI     B,0 ;set cursor to 1st col
04E0 C9         RET

; CLEAR TO LAST ROW
04E1 16 01     CLRWLP: MVI     D,1
04E3 5F         MOV      E,A      ;de=row wrap around tbl
04E4 1A         LDAX     D          ;next row
04E5 6F         MOV      L,A
04E6 CD 03DE    CTRW1: CALL     CLRROW ;clear whole row
04E9 2A 3FFC    CTRW2: LHL     LROW
04EC BD         CMP      L          ;row=lrow?
04ED C2 04E1    JNZ     CLRWLP ;until last row
04F0 C9         RET

; {FUNCTION} foreground follows
04F1 11 2020    FGDNF: LXI     D,02020h;foreground spaces
04F4 C3 04FA    JMP     LDFGD

```

```

;{FUNCTION} background follows
04F7 11 A0A0 BGNDF: LXI D,0A0A0h; background spaces
04FA 21 0000 LDF0D: LXI H,0
04FD 39 DAD SP
04FE EB XCHG
04FF 31 3F50 LXI SP,DMYROW+80
0502 C3 03EC JMP PUSHSP ;store in dummy row

```

PAGE

STARPLEX MACRO-ASSEMBLER V2.0

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CRTB01

0505

```

;{FUNCTION} insert a line
0505 CD 0590 INSLNE: CALL CRLR ;calc crow/lrow diff
0508 21 3FFA LXI H,CROW
050B 73 MOV M,E ;set crow=lrow
050C C2 054B JNZ MOVDWN ;move row contents
050F C3 058C JMP DRWZCU ;else, del lrow/zero cur

```

0512

```

;{FUNCTION} strip off a line
0512 CD 0590 STOFFLNE: CALL CRLR ;get crow/lrow diff
0515 CA 058C JZ DRWZCU ;del lrow/zero cursor
0518 E5 SLNERG: PUSH H ;else do move
0519 21 3FE7 LXI H,CPYCTL
051C 36 00 MVI M,0 ;copy upward
051E CD 0550 CALL MOVRW ;move row contents
0521 E1 POP H ;get original crow
0522 22 3FFA SHLD CROW ;back to crow
0525 C9 RET

```

0526

```

;{FUNCTION} insert/strip off line with range
0526 2A 3FFA ISLRG: LHL D CROW
0529 3A 3FA3 LDA LINP ;read 2nd parameter
052C 3D DCR A
052D E6 3F ANI 03Fh ;40/7Fh offset to 0/3Fh
052F FE 38 CPI 038h
0531 D0 RNC ;error
0532 FE 17 CPI 017h
0534 DA 053C JC ISNPA
0537 FE 20 CPI 020h
0539 DB RC ;error
053A D6 09 SUI 9
053C 3C INR A
053D 57 MOV D,A
053E 3A 3FA4 LDA LINP+1 ;read 1st parameter
0541 FE 53 CPI "S" ;strip off?
0543 7A MOV A,D
0544 CA 051B JZ SLNERG ;do strip off line
0547 CD 05C1 ILNERG: CALL IRWOS ;offset row by para
054A 7A MOV A,D ;return para
054B 21 3FE7 MOVDWN: LXI H,CPYCTL
054E 36 04 MVI M,4 ;copy downward

```

0550

```

;MOVE ROW CONTENTS,UP/DOWN CNTL BY CPYCTL
0550 F5 MOVRW: PUSH PSW ;save row count
0551 2A 3FFA LHL D CROW
0554 5E MOV E,M
0555 23 INX H
0556 56 MOV D,M
0557 1B DCX D ;crow end
0558 D5 PUSH D ;save
0559 21 3FE7 LXI H,CPYCTL;direction control
055C 11 3FFA LXI D,CROW
055F 1A LDAX D ;read crow
0560 96 SUB M ;direction cntl

```

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CRTB01

0561

```

0561 6F MOV L,A
0562 26 01 MVI H,1 ;hl=row wrap around tbl
0564 7E MOV A,M ;lookup +/- one row
0565 12 STAX D ;update crow
0566 6F MOV L,A
0567 25 DCR H ;hl=row start table
0568 5E MOV E,M
0569 23 INX H
056A 56 MOV D,M
056B 1B DCX D ;+/- row end
056C E1 POP H ;rtn current row last loc
056D 06 10 MVI B,80/5 ;copy 80 characters
056F 1A LDAX D ;read
0570 77 MOV M,A ;copy
0571 2B DCX H ;next byte
0572 1B DCX D ;next byte
0573 1A LDAX D ;do 5 times for speed
0574 77 MOV M,A

```

```

0575 2B          DCX  H
0576 1B          DCX  D
0577 1A          LDAX D      ;3
0578 77          MOV  M,A
0579 2B          DCX  H
057A 1B          DCX  D
057B 1A          LDAX D      ;4
057C 77          MOV  M,A
057D 2B          DCX  H
057E 1B          DCX  D
057F 1A          LDAX D      ;5
0580 77          MOV  M,A
0581 2B          DCX  H
0582 1B          DCX  D
0583 05          DCR  B
0584 C2 056F     JNZ  CPLP  ;finish 80 bytes?
0587 F1          POP  PSW  ;row count
0588 3D          DCR  A
0589 C2 0550     JNZ  MOVROW ;next row
058C 47          DRWZCU: MOV  B,A  ;zero cursor
058D C3 03DB     JMP  DCROW  ;and delete cursor row

```

```

;CALCULATE ROW DIFFERENCE
0590 2A 3FFA     CRLR: LHL D  CROW  ;calc crow to lrow
0593 3A 3FFC     LDA  LROW
0596 5F          FRCR: MOV  E,A
0597 95          SUB  L      ;get the difference
0598 D2 05A0     JNC  %2    ;within range
059B 3E 60      $D2: MVI  A,RWRG ;over range
059D 83          ADD  E
059E 95          SUB  L
059F B7          ORA  A      ;clear carry
05A0 1F          $2:  RAR  ;row diff /2
05A1 C9          RET

```

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CRT801 05A2

```

;{FUNCTION} address cursor
05A2 2A 3FA3     ADDCUR: LHL D  LINP  ;read leadin parameter
05A5 7C          MOV  A,H

05A6 11 5010     CALCX: LXI  D,05010h;calc x coordinate
05A9 BA          CMP  D
05AA DA 05B3     JC   CX4FD  ;00/4Fh=loc 0/79
05AD 92          SUB  D      ;50/7Fh offset to 0/2F
05AE BB          CMP  E
05AF DA 05B3     JC   CX4FD  ;50/5Fh offset to 0/15
05B2 93          SUB  E      ;60/7Fh offset to 0/31
05B3 47          CX4FD: MOV  B,A  ;then set cursor

05B4 3E 1F      CALCY: MVI  A,01Fh
05B6 A5          ANA  L      ;0/1F,20/3F,40/5F,60/7Fh
05B7 FE 1B      CPI  018h  ;offset to 00/1Fh
05B9 DA 05BE     JC   CY17D  ;00/17h=row 0/23
05BC D6 1B      SUI  018h  ;18/1Fh=row 0/7
05BE 2A 3FFE     CY17D: LHL D  FRDW  ;offset first row

05C1 07          IRWOS: RLC  ;diff*2,msb=0
05C2 85          ADD  L      ;frow+offset
05C3 DA 05CB     JC   ROSFFU  ;>FFh
05C6 FE E1      CPI  low RR48+1
05C8 DA 05CD     JC   ROSEOD  ;less than E0h,ok
05CB D6 60      ROSFFU: SUI  RWRG  ;row range
05CD 32 3FFA     ROSEOD: STA  CROW  ;then update crow
05D0 C9          RET

```

```

;{FUNCTION} read cursor
05D1 CD 05E0     RDCUR: CALL  RDX  ;read cursor x coord
05D4 CD 006D     CALL  WTACEA ;write to ace

05D7 CD 05E7     CALL  RDY  ;read cursor y coord
05DA CD 006D     CALL  WTACEA ;write to ace

05DD C3 074A     JMP  CRACE  ;cr for termination

05E0 7B          RDX:  MOV  A,B
05E1 FE 20      CPI  020h  ;if 0/1Fh add offset
05E3 D0          RNC  ;20/4Fh=cursor loc 32/79
05E4 C6 60      ADI  060h  ;60/7Fh=cursor loc 0/31
05E6 C9          RET

```



```

05E7 2A 3FFE      RDY:  LHL D   FROW
05EA 3A 3FFA      LDA   CROW
05ED CD 0596      CALL  FRCR      ; calc frow/crow diff
05FO C6 60        ADI   060h     ; 60/77h=row 0/23
05F2 C9          RET

```

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```

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CRT801
05F3

```

```

; <FUNCTION> next page
05F3 16 30      NPAGE: MVI   D, 030h ; page offset
05F5 21 3FFA   LXI   H, CROW
05FB F3        DI
05F9 7E        NPLP: MOV   A, M
05FA FE B1     CPI   0B1h
05FC DA 0601   JC   NPLT ; a< B1, B2-B0h
05FF 92       SUB   D ; a>=B1, B2-E0h
0600 92       SUB   D
0601 82       NPLT: ADD   D
0602 77       MOV   M, A
0603 2C       INR   L ; do crow/lrow/frow
0604 2C       INR   L
0605 FA 05F9   JM   NPLP ; if pass frow, end
0608 FB       EI
0609 C9       RET

; <FUNCTION> tab
060A 2A 3FFA   TAB:  LHL D   CROW
060D E5       PUSH H ; save crow
060E CD 0667   CALL SCATT

0611 13       TDADSP: INX  D ; next character
0612 2D       DCR  L ; end of row?
0613 CC 067A   CZ   DRCFL ; down one row, get 1st loc
0616 1A       LDAX D ; read character
0617 84       ADD  H ; check attribute
0618 FA 0635   JM   TSATT ; diff, find same attrib
061B FE 20     CPI   SPC ; space?
061D C2 0611   JNZ  TDAOSP ; loop until space
0620 13       TSANSP: INX  D ; next character
0621 2D       DCR  L ; end of row?
0622 CC 067A   CZ   DRCFL ; down one row, get 1st loc
0625 1A       LDAX D ; read character
0626 84       ADD  H ; check attribute
0627 FA 0635   JM   TSATT ; diff, find same attrib
062A FE 20     CPI   SPC ; non space?
062C CA 0620   JZ   TSANSP ; loop until non space
062F D1       TMCUR: POP  D ; remove saved crow
0630 3E 50     MVI  A, B0
0632 75       SUB  L ; calc cursor location
0633 47       MOV  B, A ; move cursor
0634 C9       RET
0635 13       TSATT: INX  D ; next character
0636 2D       DCR  L ; end of row?
0637 CC 067A   CZ   DRCFL ; down one row, get 1st loc
063A 1A       LDAX D ; read character
063B 84       ADD  H ; check attribute
063C FA 0635   JM   TSATT ; loop until same attrib
063F C3 062F   JMP  TMCUR ; move cursor

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CRT801
0642

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```

; <FUNCTION> clear fore/background to space
0642 2A 3FFA   CFB:  LHL D   CROW
0645 24       INR  H
0646 E5       PUSH H ; save
0647 CD 0667   CALL SCATT
064A 1A       CFBLP: LDAX D ; read character
064B 84       ADD  H ; test attribute
064C FA 0653   JM   CFBDFI ; diff attrib
064F 3E 20     MVI  A, SPC ; if same attrib,
0651 B4       ORA  H ; put a space
0652 12       STAX D
0653 13       CFBDFI: INX  D ; next character
0654 2D       DCR  L ; character counter-1
0655 C2 064A   JNZ  CFBLP ; until finish 80 char
0658 E1       POP  H ; saved crow
0659 3A 3FFC   LDA  LROW
065C BD       CMP  L ; row=lrow?
065D C8       RZ ; no more
065E 6E       MOV  L, M ; else next row
065F E5       PUSH H ; save
0660 CD 0681   CALL $3
0663 C3 064A   JMP  CFBLP
0666 C9       RET

```

```

;SET UP CHAR COUNTER AND ATTRIB
0667 CD 0174 SCATT: CALL CURLOC ;get cursor location
066A EB XCHG ;put in de
066B 21 8050 LXI H,0B050h;mask/char count
066E 3A 3F20 LDA FBG
0671 A4 ANA H
0672 67 MOV H,A
0673 22 3FA5 SHLD LINP+2 ;save count,attrib
0676 7D MOV A,L
0677 90 SUB B ;get cur to end diff
067B 6F MOV L,A ;put in l
0679 C9 RET

```

```

;DOWN ONE ROW AND GET ADDR ON 1ST COLUMN
067A CD 0463 DRCFL: CALL DCUR1 ;down cursor one row
067D CA 0033 JZ TABSTP ;crow=1row, no tab
0680 6E MOV L,M ;next row
0681 25 $3: DCR H
0682 2B $1: DCX H
0683 56 MOV D,M ;addr high
0684 2B DCX H
0685 5E MOV E,M ;addr low
0686 2A 3FA5 LHLD LINP+2 ;count and attrib
0689 C9 RET

```

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CRT801

068A

```

;{FUNCTION} graphics
068A 3A 3FA3 GRAPH: LDA LINP ;read leadin parameter
068D 21 107E LGPARA: LXI H,0107Eh
0690 3D DCR A
0691 E6 3F ANI 03Fh
0693 BC CMP H ;h=010h
0694 DA 06AD JC $G1 ;"A" to "P"
0697 FE 3E CPI 03Eh ;delete
0699 CA 06B2 JZ $G3
069C 94 SUB H ;h=010h
069D FE 0F CPI 0Fh ;space?
069F CA 06B2 JZ $G3 ;space
06A2 BC CMP H ;h=010h
06A3 DA 06AC JC $G2 ;> "Q"
06A6 FE 20 CPI 020h
06AB DA 06AD JC $G1 ;"a" to "p"
06AC 7D INR L ;set l to 7Fh
06AD CD 06D0 $G2: MOV A,L ;L=7Eh or 7Fh
06B0 C6 1E $G1: CALL STSCN ;put symbol to screen
06B2 D6 1E $G3: SUI 01Eh
06B4 32 3FF3 STA GSYMBL ;for non/destructive move

06B7 3E 80 ENGRPH: MVI A,080h
06B9 C3 06BD JMP DEGRPH+1

```

```

;{FUNCTION} defeat graphics
06BC AF DEGRPH: XRA A
06BD 32 3FEF STA GECNTL
06C0 C9 RET

```

```

;CHECK GRAPHICS MODE AND PUT SYMBOL TO SCREEN
06C1 3A 3FEF CHKGM: LDA GECNTL
06C4 B7 ORA A ;graphics mode?
06C5 C8 RZ ;no, rtn to func
06C6 3A 3FF3 LDA GSYMBL
06C9 B7 ORA A ;non destructive move?
06CA FB RM ;yes
06CB 21 3F20 STSP: LXI H,FBG
06CE AE XRA M ;get attribute
06CF AD XRA L ;remove space code
06D0 CD 0174 STSCN: CALL CURLOC
06D3 77 MOV M,A ;write to screen
06D4 C9 RET

```

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CRT801

06D5

```

;PUT GRAPHIC MENU TO SCREEN (LOCAL)
06D5 CD 070C PGM: CALL RUADD

06DB CD 06F3 CALL P3BSYM ;print ascii A/Q
06DB CD 06F3 CALL P3BSYM ;print ascii a/q

```

```

06DE CD 070C CALL RUADD
06E1 CD 0700 CALL P32SYM ;print ascii 0h/Fh
06E4 F6 7E ORI 07Eh ;print ascii 7Eh
06E6 CD 06F7 CALL P6SYM ;4 spaces
06E9 EE 30 XRI 030h ;print ascii 10/1Fh
06EB CD 0700 CALL P32SYM
06EE F6 7F ORI 07Fh ;print ascii 7Fh
06F0 C3 06F7 JMP P6SYM ;4 spaces

06F3 F6 41 P3BSYM: ORI 041h ;change symbol
06F5 16 10 MVI D,16 ;counter
06F7 14 P6SYM: INR D
06F8 CD 0702 CALL PGMLP
06FB 16 04 P4SP: MVI D,4
06FD C3 04C4 JMP DRLLP-3 ;put 4 spaces

0700 16 10 P32SYM: MVI D,16 ;print 32 symbols

0702 77 PGMLP: MOV M,A
0703 23 INX H
0704 73 MOV M,E ;FBG
0705 23 INX H
0706 3C INR A ;next symbol
0707 15 DCR D
0708 C2 0702 JNZ PGMLP
070B C9 RET

070C CD 0472 RUADD: CALL RDLUP ;up one row
070F 26 00 MVI H,0
0711 6F MDV L,A ;hl=1row
0712 CD 06B2 CALL $1 ;1row 1st loc
0715 EB XCHG
0716 CD 06FB CALL P4SP ;put 4 spaces
0719 5F MDV E,A ;FBG
071A E6 80 ANI 080h ;get attribute
071C C9 RET

```

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CRTB01

```

071D ;(FUNCTION) transmit a line
071D 06 00 SNDLNE: MVI B,0 ;set cursor to 1st loc
071F CD 0174 CALL CURLOC ;get row start
0722 E5 PUSH H ;save row start
0723 11 004F LXI D,79 ;find row end
0726 19 DAD D ;hl=row end, clear carry
0727 16 40 MVI D,040h ;rotated space
0729 7E LENDLP: MOV A,M ;read char
072A 17 RAL ;mask out msb
072B AA XRA D ;space?, clear carry
072C C2 0734 JNZ LNSP ;until find a non-space
072F 2B DCX H
0730 1D DCR E
0731 C2 0729 JNZ LENDLP ;repeat loop
0734 E1 LNSP: PDP H ;hl=row start again
0735 56 SNDLP: MOV D,M ;read character
0736 3E 60 MVI A,060h ;screen all cntl codes
0738 A2 ANA D
0739 C2 073E JNZ SNCNTL ;not control code
073C 16 2A MVI D,"*" ;cntl code, send "*" instead
073E CD 006E SNCNTL: CALL WTACED ;write to ace
0741 7E MDV A,M ;read char again
0742 EE 80 XRI 080h ;invert attribute
0744 77 MDV M,A ;store back
0745 23 INX H ;next character
0746 1D DCR E
0747 F2 0735 JP SNDLP ;until end of line

074A CD 006B CRACE: CALL SNDCR ;send cr for termination
074D 3A 3FF1 LDA LOCLM
0750 B7 ORA A ;local?
0751 C8 RZ ;remote, no time delay

0752 CD 075E $D3: CALL $DLY ;do delay
0755 15 DCR D ;d was ODh
0756 C2 0752 JNZ $D3
0759 D3 01 OUT BELPRT ;delay done, ring bell
075B C3 0463 JMP DCUR1 ;move cursor to next row
075E E5 $DLY: PUSH H
075F D5 PUSH D

```

```

0760 CD 07F0          CALL LUBD ;lookup baud constant
0763 3E 1F          MVI A,01Fh ;chg delay at high bauds
0765 B3             ORA E
0766 5F             MOV E,A
0767 CD 059B        *D1: CALL *D2
076A 1B             DCX D
076B 15             DCR D
076C 14             INR D
076D F2 0767        JP *D1
0770 D1             POP D
0771 E1             POP H
0772 C9             RET

```

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CRT801

0773

;DISPLAY CURSOR LOCATION (LOCAL)

```

0773 CD 05E7        LRDCUR: CALL RDY ;y coordinate
0776 2A 3FFC        LHL D LRLD ;get print out loc
0779 5E             MOV E,M
077A 23             INX H
077B 56             MOV D,M
077C 1B             DCX D ;row last location
077D 12             STAX D ;put to screen
077E CD 05E0        CALL RDX ;x coordinate
0781 1B             DCX D
0782 12             STAX D ;put to screen
0783 C9             RET

```

;SCALE (LOCAL)

```

0784 21 3FFE        SCALE: LXI H, FROW
0787 3A 3FFA        LDA CROW
078A BE             CMP M ;frow=crow
078B CC 048C        CZ ROLDWN ;if equ,roll down
078E 2A 3FFA        LHL D CROW ;get print out loc
0791 2B             DCX H
0792 2B             DCX H
0793 CD 0682        CALL *1
0796 EB             XCHG ;hl=loc
0797 1E 31          MVI E,"1"

```

```

0799 16 B1          SCLLP1: MVI D,"1"+0B0h
079B 3E BA          MVI A,"9"+0B1h
079D 72          SCLLP2: MOV M,D
079E 14          INR D ;"1" to "9"
079F 23          INX H ;next location
07A0 BA          CMP D ;exceeding "9"?
07A1 C2 079D        JNZ SCLLP2
07A4 3E 39          MVI A,"9"
07A6 73          MOV M,E
07A7 1C          INR E ;"1" to "8"
07AB 23          INX H ;next location
07A9 BB          CMP E ;exceeding "8"?
07AA C2 0799        JNZ SCLLP1
07AD C9          RET

```

;VERTICAL INTERRUPT CONTINUE

```

;*****
07AE 2B          VTSUB: DCX H ;VCALEN
07AF 74          MOV M,H ;h<0, enable VCAL routine
07B0 2A 3FFB        LHL D CUR ;get cursor
07B3 36 03          MVI M,3 ;write to DPB350
07B5 2A 3FF6        LHL D TOP ;top of page
07B8 36 02          MVI M,2 ;write to DPB350
07BA D3 40          OUT VERPRT ;clr vert intr flip/flop
07BC E1             POP H
07BD FB             EI
07BE C9             RET

```

PAGE

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CRT801

07BF

;(FUNCTION) ace, auto line feed, upper/lower case

```

07BF DB 40          ACESW: IN SETSW ;read switch settings
07C1 E6 10          ANI 010h
07C3 32 3FF2        STA AULF ;set auto lf flag

07C6 DB 40          IN SETSW ;read switch again
07C8 E6 20          ANI 020h
07CA C3 07D2        JMP STUL ;set u/l case flag

```

```

; INIT ACE, TOGGLE ULCASE (LOCAL)
07CD 3A 3FF0 ATGUL: LDA ULCASE
07DO EE 20 XRI 020h ;toggle u/l case
07D2 32 3FF0 STUL: STA ULCASE

07D5 CD 07F0 CALL LUBD ;lookup baud constant

07DB 21 9003 LXI H, ACECTL
07DB 74 MOV M, H ;set DLAB

07DC 2E 01 MVI L, 1
07DE 72 MOV M, D ;set baud high
07DF 2B DCX H
07E0 73 MOV M, E ;set baud low

07E1 2E 03 MVI L, 3
07E3 36 02 MVI M, 2 ;7 bit, 1 stop bit

07E5 3A 3FF1 LDA LOCLM ;local?
07E8 3C EDACE: INR A
07E9 21 9000 LXI H, ACEDTA
07EC 5E MOV E, M ;remove ace input
07ED 23 INX H ;ACEITR mask
07EE 77 MOV M, A ;en/disable ace intr
07EF C9 RET

07F0 DB 40 LUBD: IN SETSW ;lookup baud constant
07F2 E6 0E ANI 0EH
07F4 C6 FO BADDR: ADI low B110; add base addr
07F6 6F MOV L, A
07F7 26 01 MVI H, 1
07F9 5E MOV E, M ;get baud low
07FA 23 INX H
07FB 56 MOV D, M ;get baud high
07FC C9 RET
END START

```

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CRTB01

Macros:

Symbols:

*1	0682	*2	05A0	*3	06B1	*4	04A7
*5	04A9	*D1	0767	*D2	059B	*D3	0752
*DLY	075E	*G1	06AD	*G2	06AC	*G3	06B2
ACE	003B	ACECTL	9003	ACEDTA	9000	ACEDUP	001B
ACEITR	9001	ACESTU	9005	ACESW	07FB	ADDCUR	05A2
ATGUL	07CD	AULF	3FF2	B110	01F0	B1200	01F4
B19200	01FC	B2400	01F6	B3B400	01FE	B4800	01FB
B600	01F2	B9600	01FA	BADDR	07F4	BELL	0434
BELPRT	0001	BGNDF	04F7	BS	041F	BS1	0422
BSRTN	0417	C1D	023A	C7E	0240	CALCX	05A6
CALCY	05B4	CALJMP	015C	CARRTN	03B9	CB	0204
CE	020A	CFB	0642	CFBDIF	0653	CFBLP	064A
CG	020E	CHAR	0372	CHKGM	06C1	CJMP	015B
CLRR0W	03DE	CLRSCN	04CE	CLRWLP	04E1	CMRTN	025C
CPLP	056F	CPYCTL	3FE7	CG	0222	CR	000D
CRACE	074A	CRLR	0590	CROW	3FFA	CROWH	3FFB
CTLRW1	04E6	CTLRW2	04E9	CU	022A	CUR	3FFB
CUREN	3FEC	CURH	3FF9	CURLOC	0174	CURTMR	3FEB
CURULK	04AE	CX4FD	05B3	CY17D	05BE	DCROW	03DB
DCUR1	0463	DEGRPH	06BC	DEL	0419	DFCLOC	0171
DICMD	03CE	DICUR	001B	DMYROW	3F00	DRFL	067A
DRLLP	04C7	DRTLN	04C0	DRTPG	04BA	DRWZCU	05BC
DWNCUR	0460	EDACE	07EB	ENGRPH	06B7	F1	0A5F
F10	84D8	F11	85F3	F12	8472	F13	848C
F14	84AE	F15	8DD1	F16	ADA2	F17	84F1
F18	84F7	F19	836B	F2	03B9	F20	835B
F21	8505	F22	8512	F23	AD26	F24	9E8A
F25	0419	F26	83DB	F27	84C0	F28	84BA
F29	8642	F3	03B1	F30	84CE	F31	8CB6
F32	801B	F33	871D	F34	87BF	F35	0AC5
F36	86BC	F4	0C34	F5	060A	F6	0437
F7	041F	FB	844E	F9	8460	FBG	3F20
FCHR2	3780	FFCHK	0267	FFEND	3F9F	FFRD	3FE5
FFSTRT	3F50	FFWCT	3FEA	FFWRT	3FE6	FGNDF	04F1
FIFACE	004E	FRCR	0596	FR0W	3FFE	FR0WH	3FFF
FS	0437	FUNC	016B	QECNTL	3FEF	GRAPH	068A
GSYMBL	3FF3	H0MCUR	04DB	ICMD	3FEB	ILCHAR	03AB
ILELIN	02C2	ILNERG	0547	INIT	00E2	INSCHA	036B
INSHR	03BD	INSLNE	0505	INSLP	039B	IRW0S	05C1
ISLRG	0526	ISNPA	053C	JMPADD	016A	KBD	0020
KBDACE	01E4	KBDINT	02C9	KBDLCK	3FEE	KBDPRT	00B0
KBLK	04B6	KLCRTN	0260	KNACTV	0327	KULCDE	0003
LCL	02F2	LCLFUN	005F	LCLIND	0002	LDFGD	04FA
LEADIN	3FE9	LENDLP	0729	LF	000A	LFD	03C1
LFEED	03B1	LFSCR	03D2	LGPARA	06BD	LIN	8000
LINC	007E	LINEXE	02BE	LINF	3FA0	LINFH	3FA1
LINMDE	0283	LINP	3FA3	LINPFN	02A4	LINPRA	02B3

LINSET	0205	LINWCT	3FA2	LNSP	0734	LOCLM	3FF1
LRDCUR	0773	LROW	3FFC	LROWH	3FFD	LSTCHR	03C0
LUBD	07F0	MIDCHR	03B7	MOVDWN	054B	MOVRD	0550
NLC	0800	NLCSE	02EC	NOWRAP	0066	NPAGE	05F3
NPLP	05F9	NPLT	0601	NRW	3FF5	ONLINE	0345
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CRTB01							
OUTACE	0079	OVRNG	032C	P32SYM	0700	P3BSYM	06F3
P4SP	06FB	P6SYM	06F7	PATTN	0112	P9M	06D5
PGMLP	0702	PSPC	03A4	PTNLP	0117	PUSHSP	03EC
RDCUR	05D1	RDFIFO	026E	RDNEG	04A4	RDY	05E0
RDY	05E7	RFFRNG	027A	ROLDWN	048C	ROLUP	0472
ROM2	034F	ROSEOD	05CD	ROSFFU	05CB	ROW	000B
ROW1	0082	ROW10	0094	ROW11	0096	ROW12	0098
ROW13	009A	ROW14	009C	ROW15	009E	ROW16	00A0
ROW17	00A2	ROW18	00A4	ROW19	00A6	ROW2	00B4
ROW20	00AB	ROW21	00AA	ROW22	00AC	ROW23	00AE
ROW24	00B0	ROW25	00B2	ROW26	00B4	ROW27	00B6
ROW28	00BB	ROW29	00BA	ROW3	00B6	ROW2	00BC
ROW31	00BE	ROW32	00C0	ROW33	00C2	ROW34	00C4
ROW35	00C6	ROW36	00CB	ROW37	00CA	ROW38	00CC
ROW39	00CE	ROW4	00BB	ROW40	00DD	ROW41	00D2
ROW42	00D4	ROW43	00D6	ROW44	00DB	ROW45	00DA
ROW46	00DC	ROW47	00DE	ROW47D	007E	ROW48	00E0
ROW48D	00B0	ROW5	00BA	ROW6	00BC	ROW7	00BE
ROWB	0090	ROW9	0092	ROWDP	002B	ROWPRT	0040
RR1	0182	RR10	0194	RR11	0196	RR12	0198
RR13	019A	RR14	019C	RR15	019E	RR16	01A0
RR17	01A2	RR18	01A4	RR19	01A6	RR1D	01E2
RR2	0184	RR20	01AB	RR21	01AA	RR22	01AC
RR23	01AE	RR24	01B0	RR25	01B2	RR26	01B4
RR27	01B6	RR28	01BB	RR29	01BA	RR3	01B6
RR30	01BC	RR31	01BE	RR32	01C0	RR33	01C2
RR34	01C4	RR35	01C6	RR36	01CB	RR37	01CA
RR3B	01CC	RR39	01CE	RR4	01BB	RR40	01D0
RR41	01D2	RR42	01D4	RR43	01D6	RR44	01D8
RR45	01DA	RR46	01DC	RR47	01DE	RR47D	017E
RR4B	01E0	RR48D	01B0	RR5	01BA	RR6	01BC
RR7	018E	RR8	0190	RR9	0192	RTECTL	3FED
RTN	025F	RUADD	070C	RUNEG	04B4	RWRG	0060
SCALE	0784	SCATT	0667	SCLLP1	0799	SCLLP2	079D
SETSM	0040	SLNERG	0518	SNCNTL	073E	SNDCR	006B
SNDLINE	071D	SNDLP	0735	SPC	0020	START	0000
STFIFO	0244	STK	3FE5	STOFCH	035B	STOFLN	0512
STOFLP	035F	STSCN	06D0	STSP	06CB	STUL	07D2
TAB	060A	TABSTP	0033	TBLJMP	0200	TDADSP	0611
TGLCL	0333	TMCUR	062F	TOP	3FF6	TOPH	3FF7
TSANSP	0620	TSATT	0635	UCUR1	0451	ULCASE	3FF0
UPCUR	044E	VCAL	011F	VCALEN	3FF4	VERPRT	0040
VERT	0010	VERTDP	0030	VRWRAP	0061	VTSUB	07AE
W1	1000	W2	2000	WAIT	014E	WFFRNG	025A
WTACEA	006D	WTACED	006E	ZROCUR	04DE		

No Fatal error(s)

DP-XXX Advanced Graphic CRT Controller, AGCRTC

General Description

The DP-XXX advanced graphic CRT controller, AGCRTC, provides a versatile, powerful and flicker-free solution to all raster scan graphic systems.

The AGCRTC performs six major tasks:

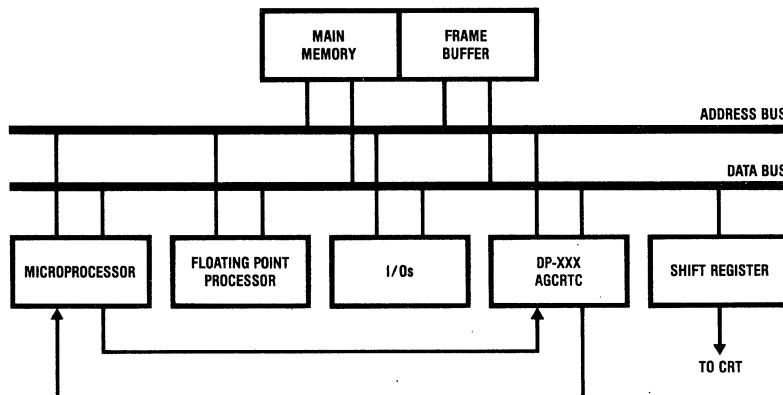
- 1) screen update
- 2) asynchronized pixel transfer
- 3) dynamic RAM refresh control
- 4) line drawing
- 5) text processing
- 6) scrolling

Multiple AGCRTCs can be used in the same system for color graphics or for faster system throughput.

Features

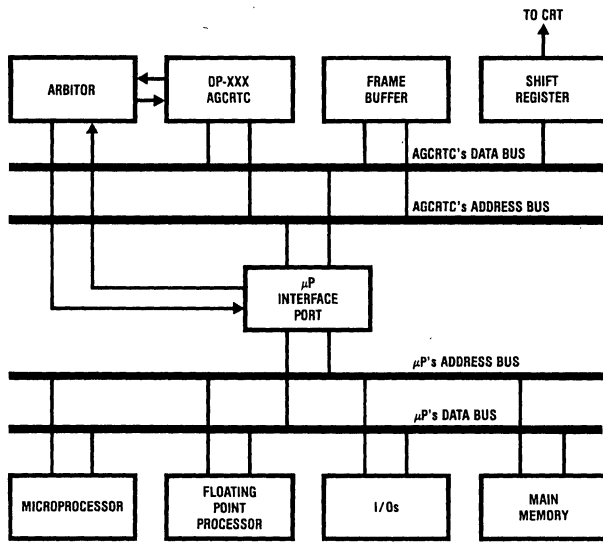
- Supports maximum 2048 pixels by 2048 lines raster scan display
- 16 or 32-bit wide data bus and 20-bit wide address bus
- Maximum frame buffer size up to 16 megapixels
- Screen parameters are programmable, including sync, blanking, screen size, etc.
- System parameters are programmable, including refresh, data bus width

- Supports both interlaced and noninterlaced raster scan displays.
- Supports BITBLT with clipping window
- Fast scrolling—a 1k by 1k display area can be scrolled in any direction within one frame time at 70 Hz, noninterlaced
- Line drawing at 200 ns per pixel
- Supports proportional spacing for word processing
- Horizontal and vertical SYNC inputs allow the AGCRTC to lock to other video sources
- AGCRTC generates either composite SYNC or separate vertical and horizontal SYNCs
- Dynamic RAM refresh support
- Supports color graphics
- Easy interfacing to all popular microprocessors
- Versatile handshake signals for maximum utilization of the available bus bandwidth
- Pipelined data input and output structures for high system throughputs
- Maximum transfer rate, 320 megapixels per second
- High-speed CMOS technology
- 68-pin leaded chip carrier



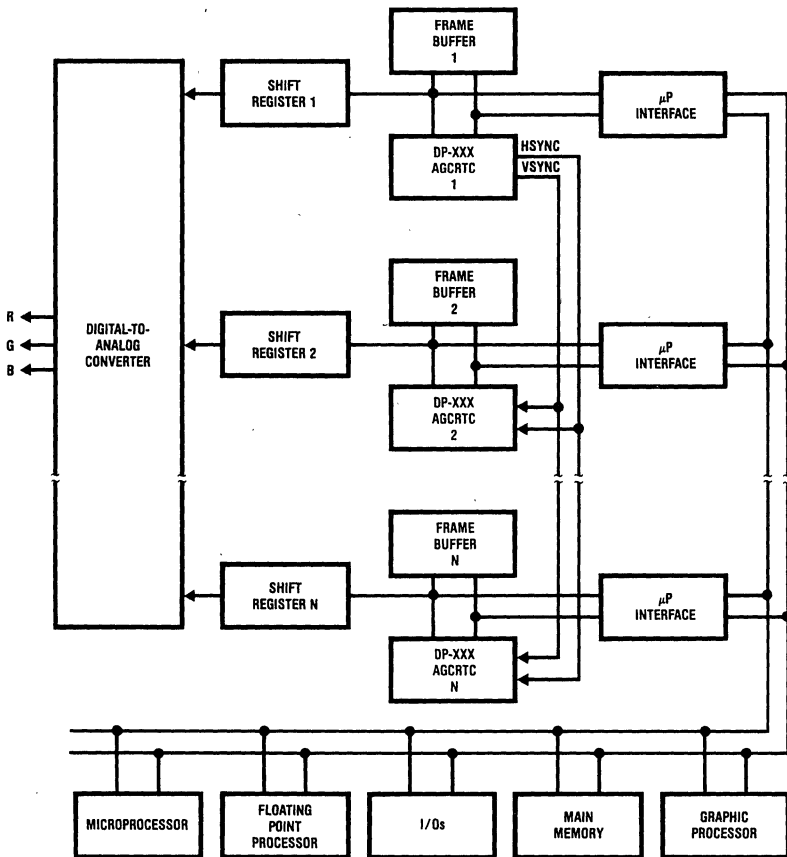
TL/F/5284-1

FIGURE 1. Single Bus System Diagram



TL/F/5284-2

FIGURE 2. Dual Bus System Diagram



TL/F/5284-3

FIGURE 3. Multiple Bitplanes, Multiple AGCRTC's System

DS75491 MOS-to-LED Quad Segment Driver
DS75492 MOS-to-LED Hex Digit Driver

General Description

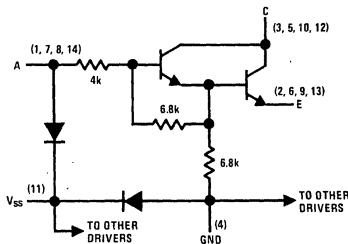
The DS75491 and DS75492 are interface circuits designed to be used in conjunction with MOS integrated circuits and common-cathode LED's in serially addressed multi-digit displays. The number of drivers required for this time-multiplexed system is minimized as a result of the segment-address-and-digit-scan method of LED drive.

Features

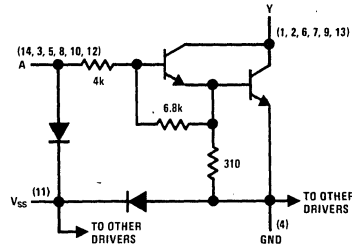
- 50 mA source or sink capability per driver (DS75491)
- 250 mA sink capability per driver (DS75492)
- MOS compatibility (low input current)
- Low standby power
- High-gain Darlington circuits

Schematic and Connection Diagrams

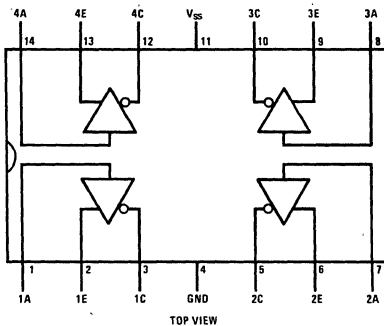
DS75491 (each driver)



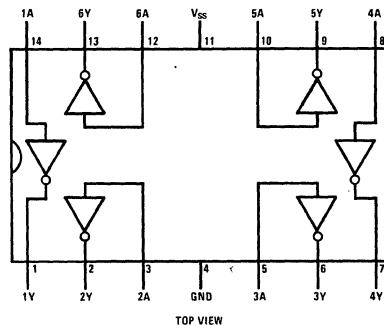
DS75492 (each driver)



DS75491 Dual-In-Line Package



DS75492 Dual-In-Line Package



Order Number DS75491J, DS75492J,
 DS75491N or DS75492N
 See NS Package J14A or N14A

Absolute Maximum Ratings (Note 1)

	DS75491	DS75492
Input Voltage Range (Note 4)	-5V to V_{SS}	-5V to V_{SS}
Collector Output Voltage (Note 5)	10V	10V
Collector Output to Input Voltage	10V	10V
Emitter to Ground Voltage ($V_I \geq 5V$)	10V	
Emitter to Input Voltage	5V	
Voltage at V_{SS} Terminal With Respect to Any Other Device Terminal	10V	10V
Collector Output Current		
Each Collector Output	50 mA	250 mA
All Collector Outputs	200 mA	600 mA
Continuous Total Dissipation	600 mW	600 mW
Operating Temperature Range	0°C to +70°C	0°C to +70°C
Storage Temperature Range	-65°C to +150°C	-65°C to +150°C
Lead Temperature (Soldering, 10 sec)	300°C	300°C
Maximum Power Dissipation at 25°C		
Cavity Package	1308 mW*	1364 mW†
Molded Package	1207 mW*	1280 mW†

*Derate cavity package 8.72 mW/°C above 25°C; derate molded package 9.66 mW/°C above 25°C.

†Derate cavity package 9.09 mW/°C above 25°C; derate molded package 10.24 mW/°C above 25°C.

Electrical Characteristics DS75491 ($V_{SS} = 10V$, $T_A = 0^\circ C$ to +70°C unless otherwise noted) (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
$V_{CE\ ON}$ "ON" State Collector Emitter Voltage	Input = 8.5V through 1 k Ω , $V_E = 5V$, $I_C = 50\ mA$		$T_A = 25^\circ C$ 0.9	1.2	V
				1.5	V
$I_{C\ OFF}$ "OFF" State Collector Current	$V_C = 10V$, $V_E = 0V$			100	μA
	$I_{IN} = 40\ \mu A$ $V_{IN} = 0.7V$			100	μA
I_I Input Current at Maximum Input Voltage	$V_{IN} = 10V$, $V_E = 0$, $I_C = 20\ mA$		2.2	3.3	mA
I_E Emitter Reverse Current	$V_{IN} = 0$, $V_E = 5V$, $I_C = 0$			100	μA
I_{SS} Current Into V_{SS} Terminal				1	mA

DS75492 ($V_{SS} = 10V$, $T_A = 0^\circ C$ to +70°C unless otherwise noted) (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{OL} Low Level Output Voltage	Input = 6.5V through 1 k Ω , $I_{OUT} = 250\ mA$		$T_A = 25^\circ C$ 0.9	1.2	V
				1.5	V
I_{OH} High Level Output Current	$V_{OH} = 10V$			200	μA
	$I_{IN} = 40\ \mu A$ $V_{IN} = 0.5V$			200	μA
I_I Input Current at Maximum Input Voltage	$V_{IN} = 10V$, $I_{OL} = 20\ mA$		2.2	3.3	mA
I_{SS} Current Into V_{SS} Terminal				1	mA

Switching Characteristics DS75491 ($V_{SS} = 7.5V$, $T_A = 25^\circ C$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-to-High Level Output (Collector)	$V_{IH} = 4.5V$, $V_E = 0$,		100		ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output (Collector)	$R_L = 200\ \Omega$, $C_L = 15\ pF$		20		ns

DS75492 ($V_{SS} = 7.5V$, $T_A = 25^\circ C$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-to-High Level Output	$V_{IH} = 7.5V$, $R_L = 39\ \Omega$,		300		ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output	$C_L = 15\ pF$		30		ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

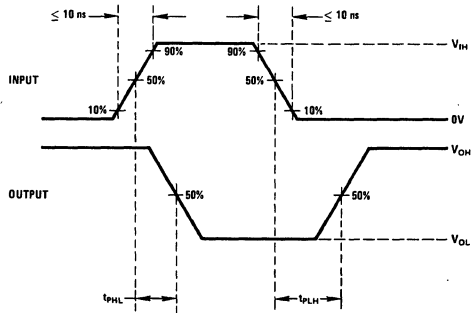
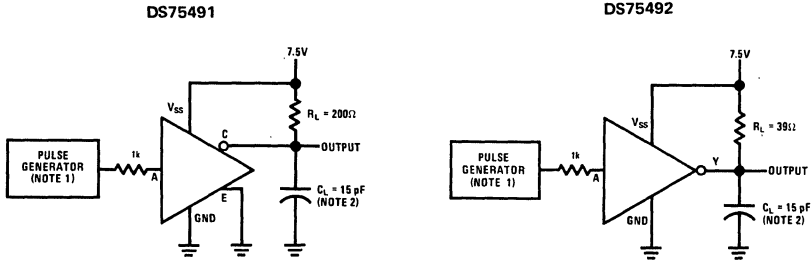
Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C temperature range for the DS75491 and DS75492.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: The input is the only device terminal which may be negative with respect to ground.

Note 5: Voltage values are with respect to network ground terminal unless otherwise noted.

AC Test Circuits and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\Omega$, $PRR = 100\text{ kHz}$, $t_W = 1\mu\text{s}$.

Note 2: C_L includes probe and jig capacitance.

DS55493/DS75493 Quad LED Segment Driver

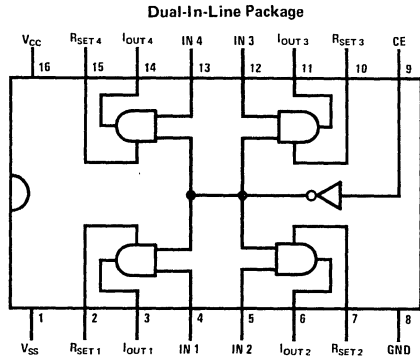
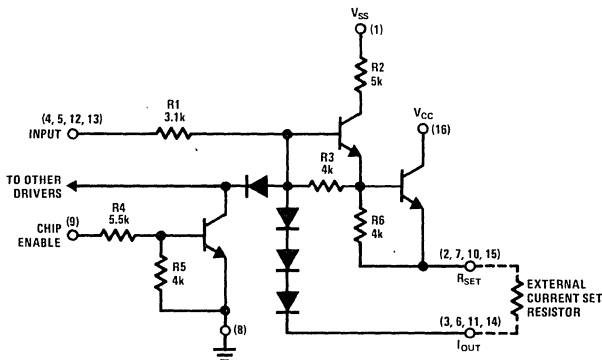
General Description

The DS55493/DS75493 is a quad LED segment driver. It is designed to interface between MOS IC's and LED's. An external resistor is required for each segment to drive the output current which is approximately equal to $0.7V/R_L$ and is relatively constant, independent of supply variations. Blanking can be achieved by taking the chip enable (CE) to a logical "1" level.

Features

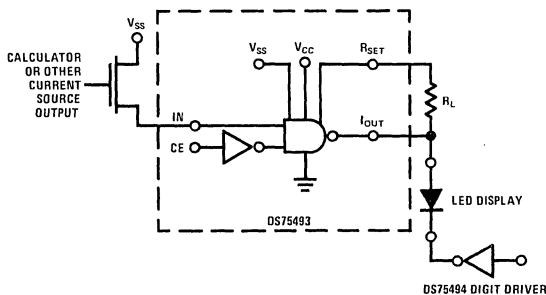
- Low voltage operation
- Low input current for MOS compatibility
- Low standby power
- Display blanking capability
- Output current regulation
- Quad high gain circuits

Schematic and Connection Diagrams



Order Number DS55493J, DS75493J
or DS75493N
See NS Package J16A or N16A

Typical Application



Truth Table

CE	V _{IN}	I _{OUT}
0	1	ON
0	0	OFF
1	X	OFF

X = Don't care

Absolute Maximum Ratings (Note 1)

Supply Voltage	10V
Input Voltage	10V
Output Voltage	V _{CC}
Storage Temperature Range	-65°C to +150°C
Output Current (I _{OUT})	-25 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1371 mW
Molded Package	1280 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.14 mW/°C above 25°C; derate molded package 10.24 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage			
V _{CC}	3.2	8.8	V
V _{SS}	6.5	8.8	V
Temperature, T _A			°C
DS75493	0	+70	°C
DS55493	-55	+125	°C

Electrical Characteristics (V_{SS} ≥ V_{CC}) (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS			
I _{IN} Input Current	V _{SS} = Max, V _{IN} = 8.8V, V _{CC} = Open, V _{CE} = 0V			3.2	mA			
	I _{OUT} = R _{SET} @ 0V, V _{CE} = 8.8V			3.6	mA			
I _{CE} Chip Enable Input Current	V _{CC} = Max, V _{SS} = Max, V _{CE} = 8.8V, All Other Pins to Gnd			2.1	mA			
I _{OUT} Output Current	I _{OUT} @ 2.15V, R _L = 50Ω	V _{CC} = Min, V _{SS} = 6.5V, I _{CE} = 80μA, V _{IN} = 6.5V Through 1.0 kΩ	-8	-13		mA		
		V _{CE} = 0V, V _{IN} = 8.8V			-16	-20	mA	
I _{OL} Output Leakage Current	I _{OUT} = R _{SET} @ 0V, Measure Current to Gnd, V _{SS} = 8.8V	V _{CC} = Min, V _{CE} = 0V, V _{IN} = 8.8V Through 100 kΩ			-100	μA		
		V _{CE} = 6.5V Through 1.0 kΩ, V _{IN} = 8.8V			-200	μA		
I _{CC} Supply Current, V _{CC}	V _{CC} = Max, V _{SS} = Max, All Other Pins to Gnd			40	μA			
I _{SS} Supply Current	V _{CC} = 0V, All Other Pins to Gnd	V _{CC} = Min, V _{SS} = 8.8V	I _{OUT} @ 2.15V, V _{CE} = 8.8V Through 100 kΩ, R _L = 50Ω		0.5	1.5	mA	
			I _{OUT} = Open, R _{SET} = Open, V _{CE} = 0V				1.4	mA

Switching Characteristics T_A = 25°C, nominal power supplies unless otherwise noted

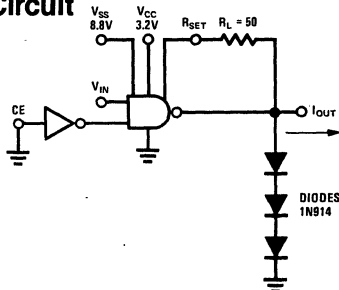
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd(OFF)} Propagation Delay to a Logical "0" From Input to Output	(See AC Test Circuit)		170	300	ns
t _{pd(ON)} Propagation Delay to a Logical "1" From Input to Output	(See AC Test Circuit)		11	100	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

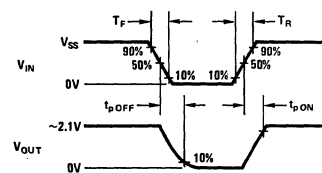
Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS75493 and across the -55°C to +125°C range for the DS55493.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

AC Test Circuit



Switching Time Waveforms



DS55494/DS75494 Hex Digit Driver

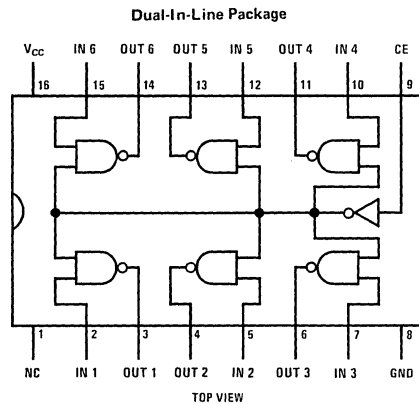
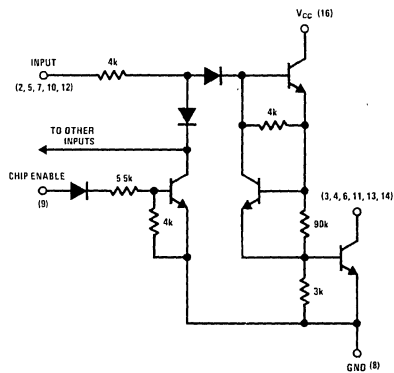
General Description

The DS55494/DS75494 is a hex digit driver designed to interface between most MOS devices and common cathodes configured LED's with a low output voltage at high operating currents. The enable input disables all the outputs when taken high.

Features

- 150 mA sink capability
- Low voltage operation
- Low input current for MOS compatibility
- Low standby power
- Display blanking capability
- Low voltage saturating outputs
- Hex high gain circuits

Schematic and Connection Diagrams



Order Number DS55494J, DS75494J
or DS75494N
See NS Package J16A or N16A

Truth Table

ENABLE	V _{IN}	V _{OUT}
0	0	1
0	1	0
1	X	1

X = don't care

Absolute Maximum Ratings (Note 1)

Supply Voltage	10V
Input Voltage	10V
Output Voltage	10V
Storage Temperature Range	-65° C to +150° C
Maximum Power Dissipation* at 25° C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300° C

*Derate cavity package 9.55 mW/° C above 25° C; derate molded package 10.9 mW/° C above 25° C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V _{CC}	3.2	8.8	V
Temperature, T _A			
DS75494	0	+70	° C
DS55494	-55	+125	° C

Electrical Characteristics (Notes 2 and 3)

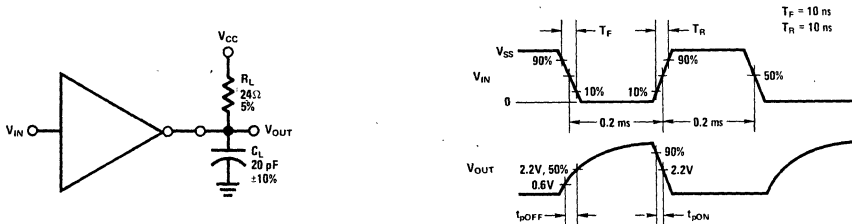
PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
I _{IH} Logical "1" Input Current	V _{CC} = Min, V _{IN} = 8.8V	V _{CE} = 8.8V through 100k			2.0	mA	
		V _{CE} = 8.8V			2.7	mA	
I _{IL} Logical "0" Input Current	V _{CC} = Max, V _{IN} = -5.5V				-20	μA	
I _{OH} Logical "1" Output Current	V _{CC} = Max, V _{OH} = 8.8V	V _{IN} = 8.8V through 100k, V _{CE} = 0V			400	μA	
		V _{IN} = 8.8V, V _{CE} = 6.5V through 1.0k			400	μA	
V _{OL} Logical "0" Output Voltage	V _{CC} = Min, I _{OL} = 150 mA, V _{IN} = 6.5V through 1.0k, V _{CE} = 8.8V through 100k	DS75494		0.25	0.35	V	
		DS55494		0.25	0.4	V	
I _{CC} Supply Current	V _{CC} = Max	One Driver "ON", V _{IN} = 8.8V	DS75494		8.0	mA	
			DS55494		10.0	mA	
		All Other Pins to GND	V _{CE} = 6.5V through 1.0k			100	μA
			V _{IN} = 8.8V through 100k			100	μA
All Other Pins to GND				40	μA		
t _{OFF} Output "OFF" Time	C _L = 20 pF, R _L = 24Ω, V _{CC} = 4.0V, See ac Test Circuits			0.04	1.2	μs	
t _{ON} Output "ON" Time	C _L = 20 pF, R _L = 24Ω, V _{CC} = 4.0V, See ac Test Circuits			13	100	ns	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0° C to +70° C range for the DS75494 and across the -55° C to +125° C range for the DS55494.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

AC Test Circuit and Switching Time Waveforms



DS8654 8-Output Display Driver (LED, VF, Thermal Printer) DS8656 Diode Matrix

General Description

DS8654 is an 8-digit driver with emitter/follower outputs. It can source up to 50 mA at a low impedance, and operates with a constant internal drive current over a wide range of power supply—from 4.5V to 33V. The DS8654 can be used to drive electrical or mechanical, multiplexed or unmultiplexed display systems. It can be used as a segment driver for common cathode displays with external current limiting resistors or can drive incandescent or fluorescent displays directly, both digits (anodes) and segments (grids). It will be necessary to run the device at a lower duty cycle, to keep the maximum package dc power dissipation less than 600 mW while operating all 8 outputs at high supply voltage and large source current. The inputs are MOS compatible and eliminate the need for level shifting since inputs are referenced to the most negative supply of system.

System Description

The DS8654 and DS8656 are specifically designed to operate a thermal printing head for calculator or other

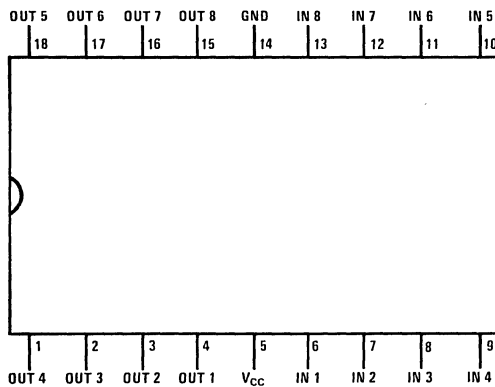
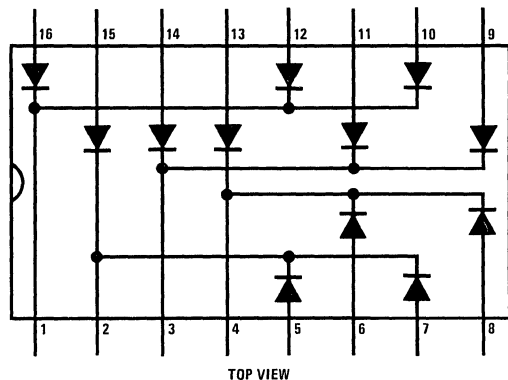
uses. In this application the same segment in each digit is selected at the same time, reducing the overall time for a complete print cycle. The DS8654 is an 8-digit driver. With a 15-digit print head, two of the DS8654 are required.

The DS8656 diode arrays are used to prevent "sneak" currents in the resistive print head. In a 15-digit print head with one alphanumeric digit there are 119 resistor segments requiring 119 diodes. For ease of assembly, the DS8656 is configured in four groups of three common cathode diodes in each group. In the system, ten parts of DS8656 are required.

The whole system is designed to operate from a +19V supply for the print head and an 8-cell nickel-cadmium battery supplying -8V to -11.6V for the rest of the electronics. The 8-segment drive transistors require V_{CER} 's of 33V min, β of > 100 at $I_C = 500$ mA, and $V_{SAT} \leq 1.0V$ at 800 mA with 15 mA drive.

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Connection Diagrams

Dual-In-Line Package

**Order Number DS8654N
See NS Package N18A**
Dual-In-Line Package

**Order Number DS8656N
See NS Package N16A**

Absolute Maximum Ratings DS8654 (Note 1)

Supply Voltage	36V
Input Voltage	36V
Output Voltage	$V_{CC} - 36V$
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation at 25°C	
Molded Package (DS8654)*	1563 mW
Molded Package (DS8656)†	1280 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions DS8654

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	4.5	33	V
Temperature (T_A)	0	+70	°C

*Derate molded package 12.5 mW/°C above 25°C.

†Derate molded package 10.24 mW/°C above 25°C.

Electrical Characteristics DS8654 (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
I_{IH}	Logical "1" Input Current		390	500	μA
I_{IL}	Logical "0" Input Current		13	40	μA
I_{OFF}	"Off" State Leakage Current		0.01	-100	μA
V_{ON}	"On" State Output Voltage		$V_{CC}-1.8$	$V_{CC}-2.5$	V
$I_{CC(OFF)}$	Supply Current		0.01	1.0	mA
$I_{CC(ON)}$	Supply Current (All Outputs "ON")		7.5	10	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

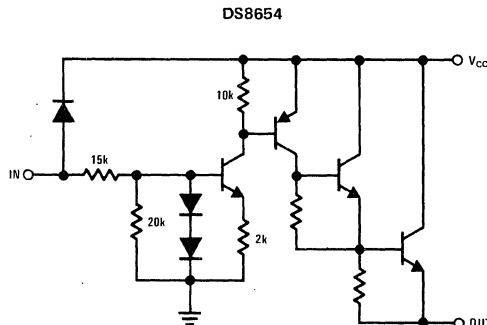
Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS8654. All typicals are given for $V_{CC} = 30V$ and $T_A = 25^\circ C$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Electrical Characteristics DS8656 ($T_A = 0^\circ C$ to +70°C)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_R	Peak Inverse Voltage	35			V
V_F	Forward Voltage			1.5	V
t_r	Reverse Recov. Time			1.0	μs

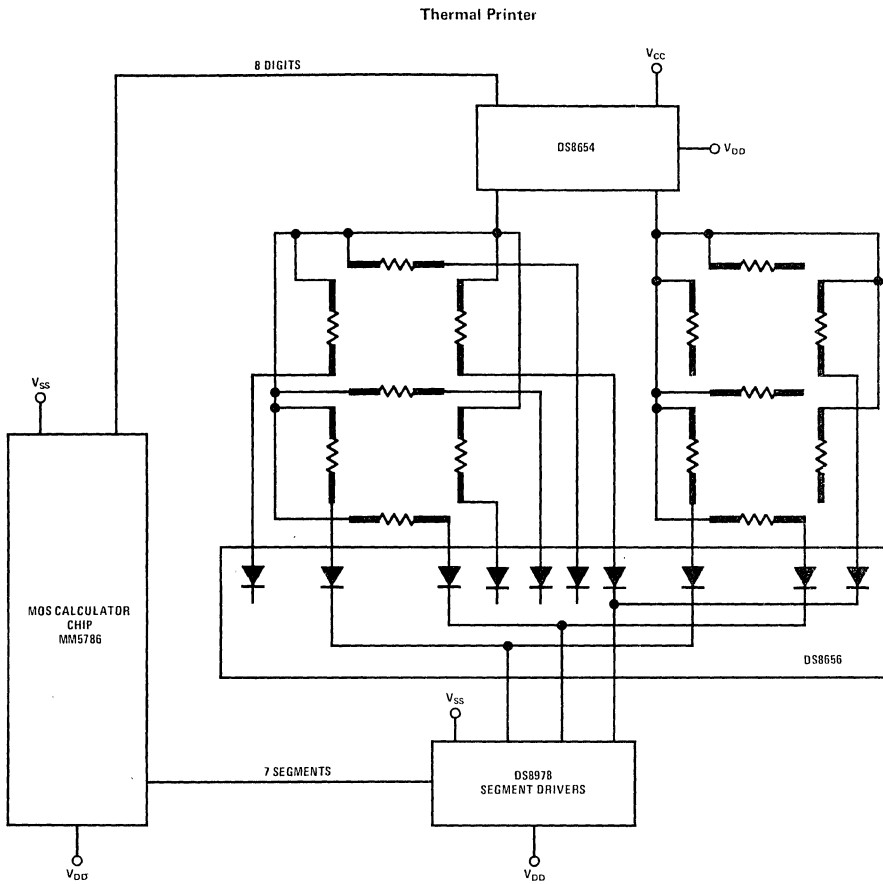
Schematic Diagram



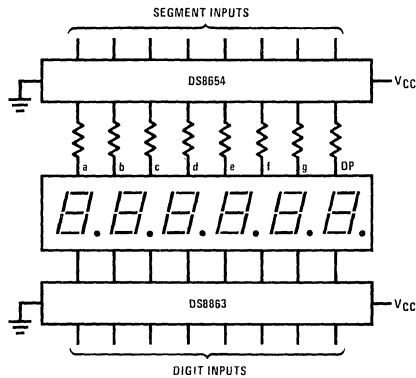
Typical Applications

DS8654, DS8656

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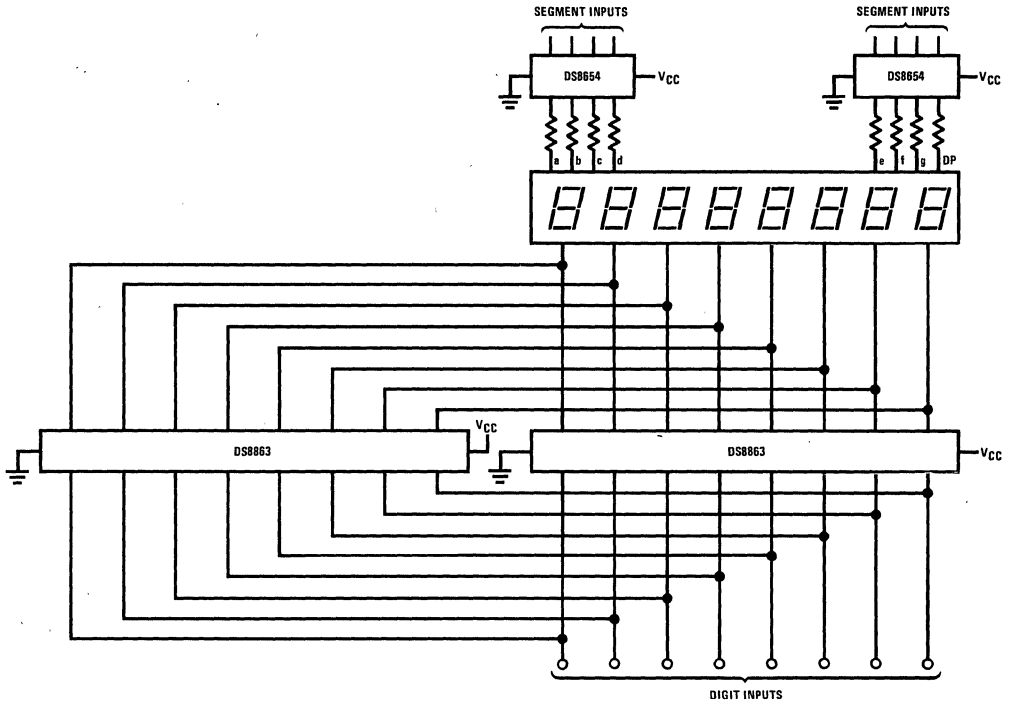


LED Display—0 mA to 50 mA Peak Segment Current

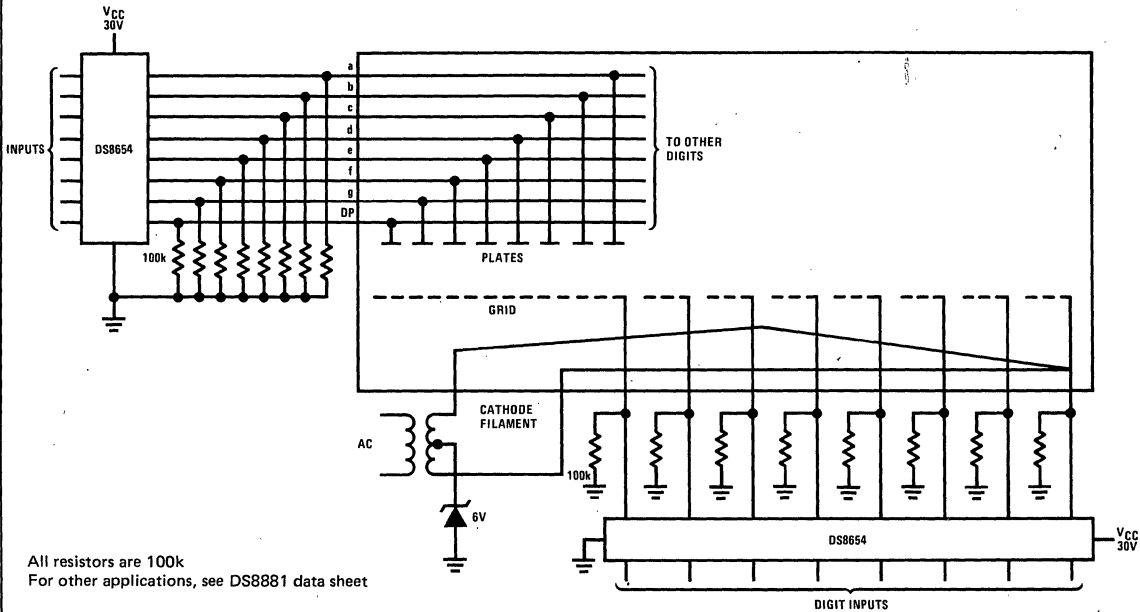


Typical Applications (Continued)

LED Display—50 mA to 100 mA Peak Segment Current



VF Display



All resistors are 100k
For other applications, see DS8881 data sheet

DS8664 14-Digit Decoder/Driver With Low Battery Indicator

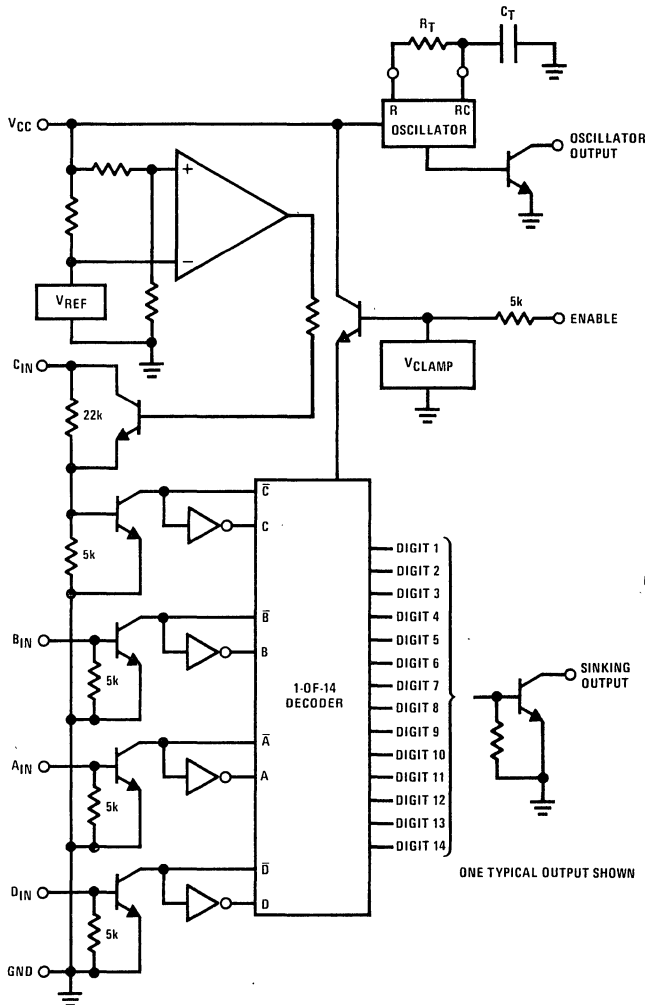
General Description

The DS8664 circuit is a 14-digit decoder/driver with an 80 mA sink capability. The circuit has current threshold inputs, and is designed to be driven by P-channel MOS. The enable input permits interdigit blanking of the decoded outputs. An open-collector output oscillator is provided for system timing (two passive external components are required). A low-battery indicator is provided at the "C" input with a nominal trip point of 3.25V at 25°C.

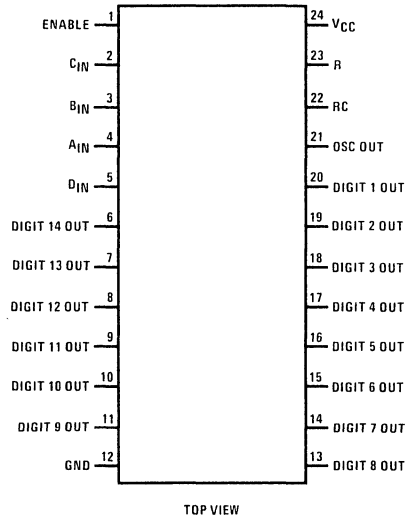
Features

- Oscillator frequency accuracy allows maximum system speed
- Inter-digit blanking with the enable input provides ghost-free display operation
- Low-battery indicator accuracy provides consistent low-battery indication

Logic and Connection Diagrams



Dual-In-Line Package



Order Number DS8664N
See NS Package N24A

Absolute Maximum Ratings (Note 1)

Supply Voltage	10V
Input Voltage	±10V
Input Current	±1.5 mA
Output Voltage	10V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	2005 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 16.04 mW/°C above 25°C.

Operating Conditions

Supply Voltage (V _{CC})	MIN 2.9	MAX 9.5	UNITS V
Temperature (T _A)	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH}	Logical "1" Input Voltage Decoder Inputs	V _{CC} = Max, V _{ENABLE} = 4.9V	I _{IN} = 260μA	0.50		V	
			I _{IN} = 1400μA			1.50	V
V _{IH}	Enable Input	V _{CC} = Max, I _{ENABLE} = 260μA, T _A = 25°C	3.0	4.2	5.1	V	
I _{IH}	Logical "1" Input Current Decoder Inputs	V _{CC} = Max, V _{ENABLE} = 4.9V	260			μA	
I _{IH}	Enable Input	V _{CC} = Max	260			μA	
V _{IL}	Logical "0" Input Voltage	V _{CC} = Max, V _{ENABLE} = 4.9V, I _{IL} = 25μA	A _{IN} , B _{IN} , D _{IN}			0.30	V
			C _{IN}			0.50	V
I _{IL}	Logical "0" Input Current	V _{CC} = Max, V _{ENABLE} = 4.9V, V _{IL} = Max			25	μA	
V _{OH}	C Input (Low-Battery Output)	V _{CC} = 3.1V, T _A = 25°C	I _{IN} = 300μA	4.9	7.3		V
			I _{IN} = 400μA	6.5	10.0		V
V _{OL}	C Input (Low-Battery Output)	V _{CC} = 3.4V, I _{IN} = 1300μA, T _A = 25°C		1.0	3.0	V	
I _{OH}	Logical "1" Output Current Except Pin R	V _{CC} = Max, V _{OH} = 10.0V, V _{ENABLE} = 4.9V V _{RC} = 0.6V			50	μA	
I _{OS}	Output Short Circuit Current Pin R Only	V _{CC} = Max, V _{RC} = 0.6V	-0.15	-0.28	-0.45	mA	
V _{OL}	Logical "0" Output Voltage Digit Outputs	V _{CC} = Min, I _{OL} = 80 mA, V _{ENABLE} = 4.9V		0.35	0.55	V	
V _{OL(OSC)}	Oscillator Output	V _{CC} = Min, I _{OL} = 6 mA, V _{RC} = 1.5V		0.20	0.55	V	
V _{OL}	Pin R	V _{CC} = Min, I _{OL} = 60μA, V _{RC} = 1.5V		0.10	0.25	V	
I _{CC}	Supply Current—Enabled	V _{CC} = Max, V _{ENABLE} = 4.9V		15.0	22.0	mA	
I _{CC}	Supply Current—Disabled	V _{CC} = Max, V _{ENABLE} = 1.0V		6.0	12.0	mA	
f _{OSC}	Oscillator Frequency	R _T = 35k ±2%, C _T = 100 pF ±5%, V _{CC} = Min to 4.5V	300	350	400	kHz	
		R _T = 33k ±2%, C _T = 100 pF ±5%, V _{CC} = 7.9V to Max	320	360	400	kHz	
D.C.	Duty Cycle (t _{PWH} /τ)	R _T = 35k ±2%, C _T = 100 pF ±5%, V _{CC} = Min to 4.5V	0.46	0.56	0.66		
		R _T = 33k ±2%, C _T = 100 pF ±5%, V _{CC} = 7.9V to Max	0.46	0.56	0.66		

Switching Characteristics V_{CC} = 4.0V, T_A = 25°C unless otherwise specified.

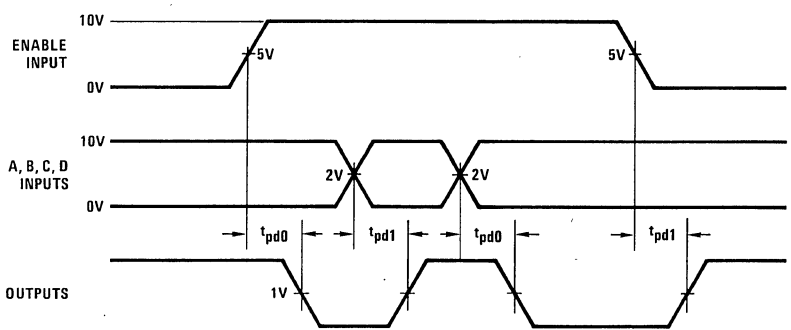
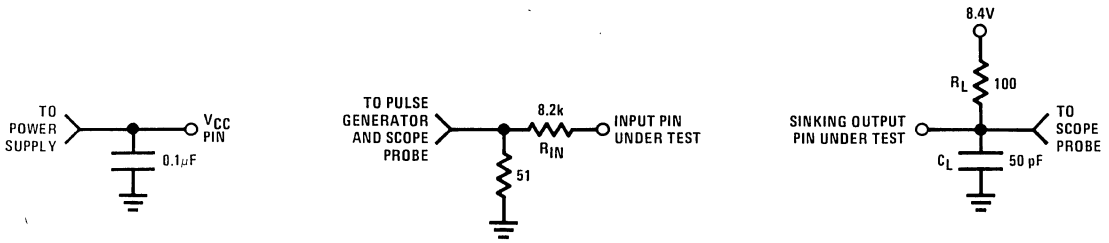
PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd1} or t _{pd0}	Propagation Delay From A, B, C, D Inputs to Digit Outputs	R _{IN} = 8.2k, V _{ENABLE} = 10V, R _L = 100Ω, C _L = 50 pF			500	ns
t _{pd0}	Propagation Delay to a Logical "0" From Enable Input to Digit Outputs	R _{IN} = 8.2k, R _L = 100Ω, C _L = 50 pF	30	80	200	ns
t _{pd1}	Propagation Delay to a Logical "1" From Enable Input to Digit Outputs	R _{IN} = 8.2k, R _L = 100Ω, C _L = 50 pF	100	250	500	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C range; all typical values are given for V_{CC} = 4.0V and T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

AC Test Circuits and Switching Time Waveforms



Note: Input voltage rise and fall times are 120 ns from 10% to 90% points.

Truth Table

A _{IN}	B _{IN}	C _{IN}	D _{IN}	DIG. OUT ON
0	0	0	0	NONE
1	0	0	0	1
0	1	0	0	2
1	1	0	0	3
0	0	1	0	4
1	0	1	0	5
0	1	1	0	6
1	1	1	0	7
0	0	0	1	8
1	0	0	1	9
0	1	0	1	10
1	1	0	1	11
0	0	1	1	12
1	0	1	1	13
0	1	1	1	14
1	1	1	1	NONE

DS8666 14-Digit Decoder/Driver

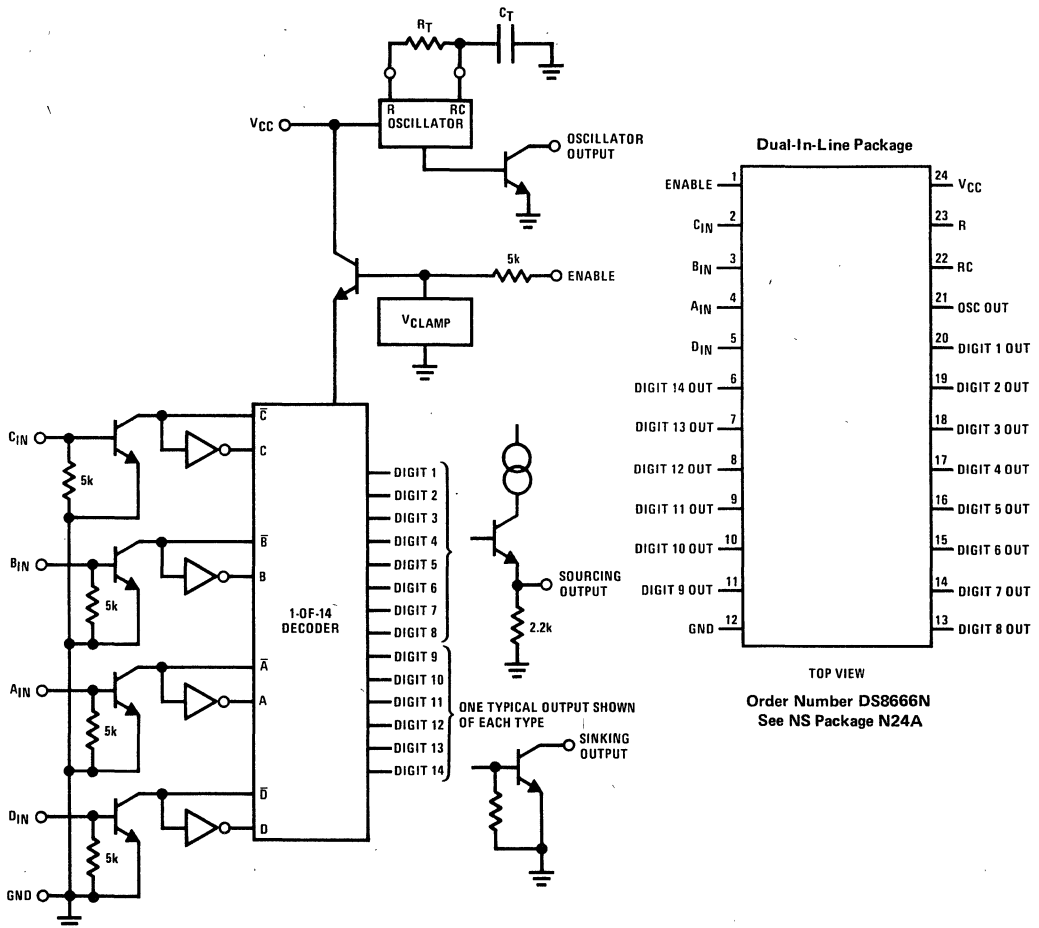
General Description

The DS8666 circuit is a 14-digit decoder/driver. Six outputs have an 80 mA sink capability, and eight of the outputs have a 13 mA nominal source drive capability to drive external grounded-emitter transistor bases. The circuit has current threshold inputs, and is designed to be driven by P-channel MOS. An enable input is provided to allow for inter-digit blanking of the decoded outputs. An open-collector output oscillator is provided for system timing (two passive external components are required).

Features

- Oscillator frequency accuracy allows maximum system speed
- Inter-digit blanking with the enable input provides ghost-free display operation

Logic and Connection Diagrams



Absolute Maximum Ratings (Note 1)

Supply Voltage	10V
Input Voltage	10V
Input Current	±1.5 mA
Output Voltage	10V
Storage Temperature Range	-65° C to +150° C
Maximum Power Dissipation* at 25° C	
Molded Package	2005 mW
Lead Temperature (Soldering, 10 seconds)	300° C

*Derate molded package 16.04 mW/° C above 25° C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	7.9	9.5	V
Temperature (T _A)	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH}	Logical "1" Input Voltage Decoder Inputs	V _{CC} = Max, V _{ENABLE} = 6.7V	I _{IN} = 390 μA	0.50		V	
			I _{IN} = 1400 μA			1.50	V
V _{IH}	Enable Input	V _{CC} = Max, I _{ENABLE} = 140 μA	5.0	6.3	7.0	V	
I _{IH}	Logical "1" Input Current Decoder Inputs	V _{CC} = Max, V _{ENABLE} = 6.7V	390			μA	
I _{IH}	Enable Input	V _{CC} = Max	140			μA	
V _{IL}	Logical "0" Input Voltage	V _{CC} = Max, V _{ENABLE} = 6.7V, I _{IL} = 25 μA			0.30	V	
I _{IL}	Logical "0" Input Current	V _{CC} = Max, V _{ENABLE} = 6.7V, V _{IL} = Max			25	μA	
I _{OH(OSC)}	Oscillator Output	V _{CC} = Max, V _{OH} = 10.0V, V _{RC} = 0.6V			50	μA	
I _{OH}	Digit 1–8 Outputs	V _{CC} = Max, V _{OH} = 1.00V, V _{ENABLE} = 6.7V	-7.0	-13.0	-20.0	mA	
I _{OH}	Logical "1" Output Current Digit 9–14 Outputs	V _{CC} = Max, V _{OH} = 10.0V, V _{ENABLE} = 6.7V			50	μA	
I _{OS}	Output Short-Circuit Current Pin R Only	V _{CC} = Max, V _{RC} = 0.6V	-0.15	-0.30	-0.45	mA	
V _{OL(OSC)}	Oscillator Output	V _{CC} = Min, I _{OL} = 6 mA, V _{RC} = 1.5V			0.50	V	
V _{OL}	Logical "0" Output Voltage Digit 1–8 Outputs Digit 9–14 Outputs Pin R	V _{CC} = Min, V _{ENABLE} = 6.7V	I _{OL} = 40 μA			0.40	V
			I _{OL} = 80 mA		0.35	0.50	V
			I _{OL} = 60 μA, V _{RC} = 1.5V		0.10	0.20	V
I _{CC}	Supply Current—Enabled	V _{CC} = Max, V _{ENABLE} = 6.7V, V _{OH} = 1.00V, (Sourcing Output "ON")		26.0	35.0	mA	
I _{CC}	Supply Current—Disabled	V _{CC} = Max, V _{ENABLE} = 1.0V		5.0	7.0	mA	
f _{OSC}	Oscillator Frequency	R _T = 33k ±2%, C _T = 100 pF ±5% V _{CC} = Min V _{CC} = Max	320	360	400	kHz	
D.C.	Duty Cycle (t _{PWH} /τ)	R _T = 33k ±2%, C _T = 100 pF ±5% V _{CC} = Min V _{CC} = Max	0.46	0.56	0.66		

Switching Characteristics V_{CC} = 8.4V, T_A = 25° C

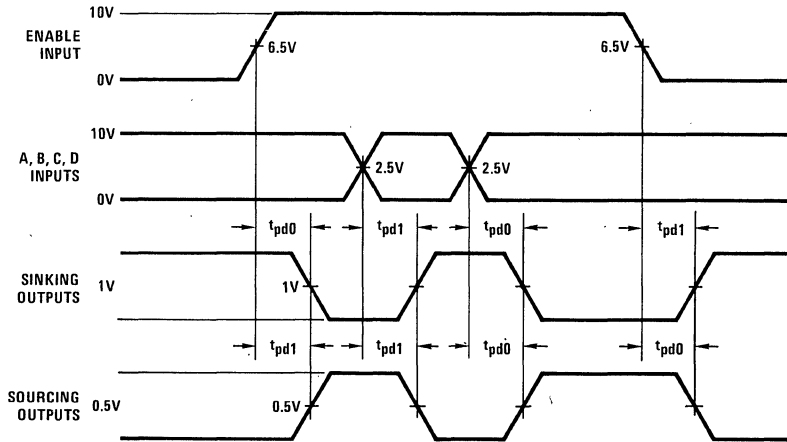
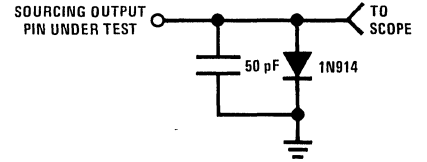
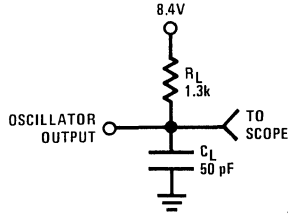
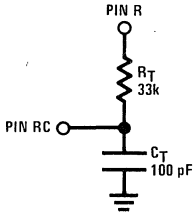
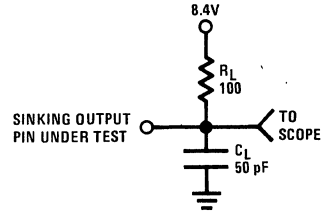
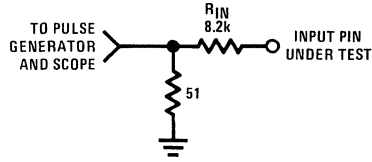
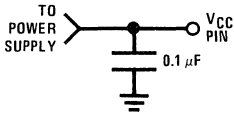
PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
t _{pd0} or t _{pd1}	Propagation Delay From A, B, C, D Inputs to Digit Outputs	R _{I(N)} = 8.2k, V _{ENABLE} = 10V, C _L = 50 pF			500	ns
t _{pd0} or t _{pd1}	Propagation Delay From Enable Input to Digit Outputs	R _{I(N)} = 8.2k, C _L = 50 pF			500	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0° C to +70° C for the DS8666. All typicals are given for V_{CC} = 8.4V and T_A = 25° C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

AC Test Circuits and Switching Time Waveforms



Note. Input rise and fall times are 120 ns between 10% and 90% points.

Truth Table

A _{IN}	B _{IN}	C _{IN}	D _{IN}	DIG. OUT ON
0	0	0	0	NONE
1	0	0	0	1
0	1	0	0	2
1	1	0	0	3
0	0	1	0	4
1	0	1	0	5
0	1	1	0	6
1	1	1	0	7
0	0	0	1	8
1	0	0	1	9
0	1	0	1	10
1	1	0	1	11
0	0	1	1	12
1	0	1	1	13
0	1	1	1	14
1	1	1	1	NONE

DS8669 2-Digit BCD to 7-Segment Decoder/Driver

General Description

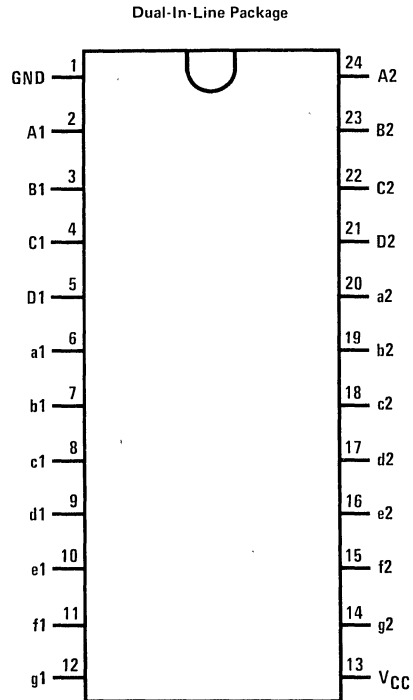
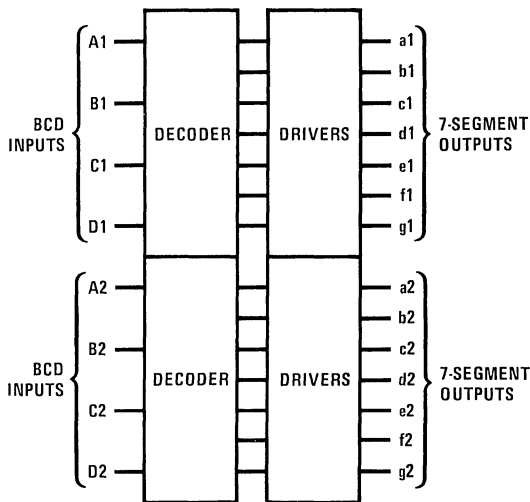
The DS8669 is a 2-digit BCD to 7-segment decoder/driver for use with common anode LED displays. The DS8669 drives 2 7-segment LED displays without multiplexing. Outputs are open-collector, and capable of sinking 25 mA/segment. Applications include TV and CB channel displays.

Features

- Direct 7-segment drive
- 25 mA/segment current sink capability
- Low power requirement—16 mA typ
- Very low input currents—2 μ A typ
- Input clamp diodes to both V_{CC} and ground
- No multiplexing oscillator noise

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Logic and Connection Diagrams



TOP VIEW

Order Number DS8669N
See NS Package N24A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Current	20 mA
Output Voltage	12V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	2005 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 16.04 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	4.5	6.0	V
Temperature (T_A)	0	+70	°C

Electrical Characteristics $V_{CC} = 5.25V$, (Note 2)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{IH}	Logical "1" Input Voltage	$V_{CC} = \text{Min}$	2.0	$V_{CC}+0.6$	V
V_{IL}	Logical "0" Input Voltage	$V_{CC} = \text{Min}$	-0.3	0.8	V
I_o	Logical "1" Output Leakage Current	$V_{CC} = \text{Max}$, $V_{OUT} = 10V$		50	μA
V_{OL}	Logical "0" Output Voltage	$I_{OL} = 25 \text{ mA}$, $V_{CC} = \text{Min}$	0.4	0.8	V
I_{IH}	Logical "1" Input Current	$V_{IN} = V_{CC} = \text{Max}$	2.0	10	μA
I_{IL}	Logical "0" Input Current	$V_{IN} = 0V$, $V_{CC} = \text{Max}$	-0.1	-10	μA
I_{CC}	Supply Current	All Outputs Low, $V_{CC} = \text{Max}$	16	25	mA
V_{IC}	Input Clamp Voltage	$I_{IN} = 10 \text{ mA}$		$V_{CC}+1.5V$	V
		$I_{IN} = -10 \text{ mA}$		-1.5	V
t_{pd0}	Propagation Delay to a Logical "0" From Any Input to Any Output	$R_L = 400\Omega$ $C_L = 50 \text{ pF}$ $T_A = 25^\circ C$		10	μs
				10	μs
t_{pd1}	Propagation Delay to a Logical "1" From Any Input to Any Output				

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS8669. All typicals are given for $V_{CC} = 5.25V$ and $T_A = 25^\circ C$.

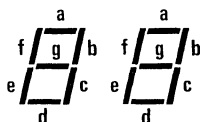
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Truth Table

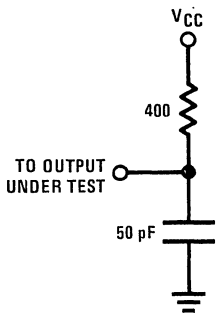
INPUT LEVELS				SEGMENT OUTPUTS															
D _N	C _N	B _N	A _N	a1	b1	c1	d1	e1	f1	g1	a2	b2	c2	d2	e2	f2	g2	DISPLAY 1	DISPLAY 2
0	0	0	0	0	0	0	0	0	0	1	0	0	0	0	0	0	1	0	0
0	0	0	1	1	0	0	1	1	1	1	1	0	0	1	1	1	1	1	1
0	0	1	0	0	0	1	0	0	1	0	0	0	1	0	0	1	0	2	2
0	0	1	1	0	0	0	0	1	1	0	0	0	0	0	1	1	0	3	3
0	1	0	0	1	0	0	1	1	0	0	1	0	0	1	1	0	0	4	4
0	1	0	1	0	1	0	0	1	0	0	0	1	0	0	1	0	0	5	5
0	1	1	0	0	1	0	0	0	0	0	0	1	0	0	0	0	0	6	6
0	1	1	1	0	0	0	1	1	1	1	0	0	0	1	1	1	1	7	7
1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	8	8
1	0	0	1	0	0	0	0	1	0	0	0	0	0	0	1	0	0	9	9
1	0	1	0	0	1	1	0	0	0	1	1	0	0	1	0	0	0	C	H
1	0	1	1	0	0	0	1	0	0	0	1	0	0	0	0	1	1	A	J
1	1	0	0	0	0	1	1	0	0	0	1	1	1	1	0	0	0	1	P
1	1	0	1	0	1	1	0	0	0	0	0	1	1	1	1	0	0	E	F
1	1	1	0	1	1	1	1	1	1	0	1	1	1	1	1	1	0	-	-
1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	(Blank)	(Blank)

"0" = Segment ON
 "1" = Segment OFF

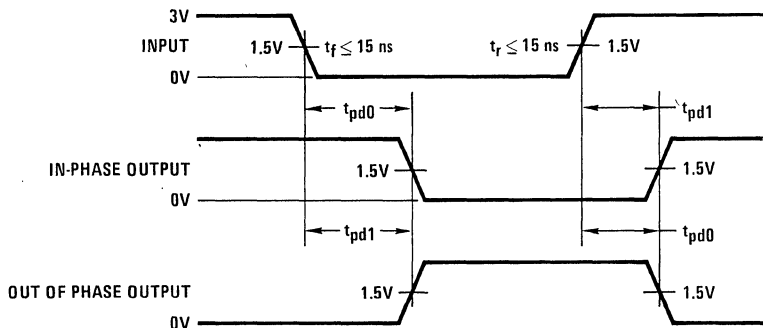
Display Segment Notation



AC Test Circuit



Switching Time Waveforms



DS8692, DS8693, DS8694 Printing Calculator Interface Set

General Description

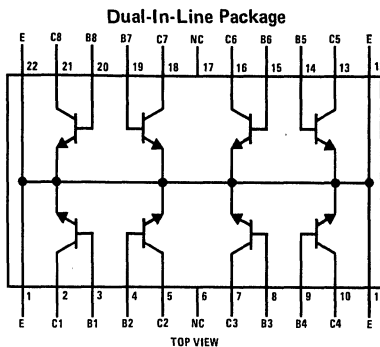
Two DS8692 IC's and one each of the DS8693 and DS8694 provide the complete interface necessary between the MM5787 calculator chip and the Seiko Model 310 printing head. The DS8692 is an array of eight common emitter output transistors each capable of sinking 350 mA, with open collector saturating outputs. The DS8693 contains the interface logic for the color solenoid driver, motor driver, and 7-column character select solenoid drivers. The DS8694 contains the interface logic for 8-column solenoid drivers plus the clock oscillator and timing signal buffer. The color and character select solenoid latch outputs of both are

constant current outputs supplying the base current for the DS8692 arrays. These outputs also feature active pull-down. The motor drive latch output is an open collector capable of sinking 20 mA.

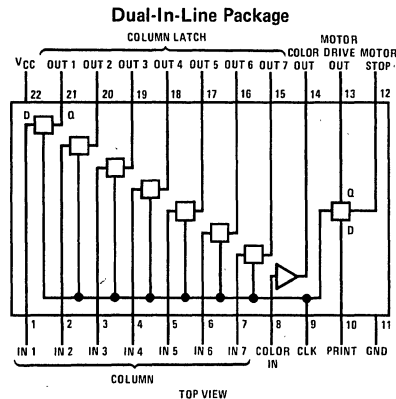
Features

- Provides complete interface package for printing calculators with minimum number of packages and minimum number of external components
- 350 mA sink capability

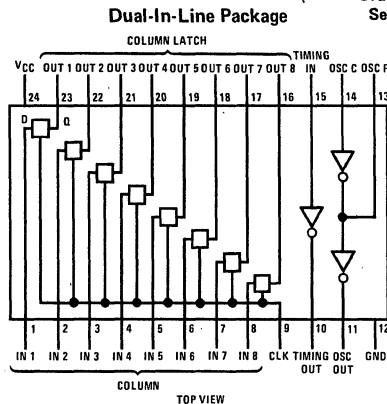
Connection Diagrams



Order Number DS8692N
See NS Package N22A



Order Number DS8693N
See NS Package N22A



Order Number DS8694N
See NS Package N24A

Absolute Maximum Ratings DS8692—Transistor Array (Note 1)

Collector to Base Voltage	25V	Power Dissipation ($T_A = 25^\circ\text{C}$)	650 mW
Collector to Emitter Voltage	25V	Operating Junction Temperature	150°C max
Collector to Emitter Voltage (Note 4)	15V	Operating Temperature Range	0°C to +70°C
Emitter to Base Voltage	6V	Storage Temperature Range	-65°C to +150°C
Collector Current (Continuous)	0.4A	Lead Temperature (Soldering, 10 seconds)	300°C

Electrical Characteristics DS8692 (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{CEO}	Collector to Emitter Breakdown Voltage $I_C = 500 \mu\text{A}, I_B = 0$	15			V
V _{CES}	Collector to Emitter Breakdown Voltage $I_C = 1 \text{ mA}, V_{BE} = 0$	25			V
V _{CBO}	Collector to Base Breakdown Voltage $I_C = 1 \text{ mA}, I_E = 0$	25			V
V _{CE(SAT)}	Collector to Emitter Saturation Voltage $I_C = 350 \text{ mA}, I_B = 7.0 \text{ mA}$, (Note 7)		0.6	1.0	V
V _{BE(SAT)}	Base to Emitter Saturation Voltage $I_C = 350 \text{ mA}, I_B = 7.0 \text{ mA}$, (Note 7)		0.8	1.05	V

Absolute Maximum Ratings DS8693 (Note 1)

Supply Voltage	12V
Input Voltage	12V
Output Voltage	
All Pins Except Pin 13	12V
Pin 13	19V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1897 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 15.18 mW/°C above 25°C.

Operating Conditions DS8693

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	8.5	11.0	V
Temperature (T_A)	0	+70	°C

Electrical Characteristics DS8693 (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
COLUMN DRIVERS					
I _{IN}	Input Current	$V_{IN} = 2.7\text{V}$	50		μA
		$V_{IN} = 9.5\text{V}$		250	μA
V _{OL}	Output OFF Voltage	$V_{CC} = \text{Min}, V_{IN} = 2.7\text{V}, V_{\text{CLOCK}} = 3.5\text{V}, I_{\text{OUT}} = 1 \text{ mA}$		0.4	V
I _{OH}	Output ON Current	$V_{CC} = \text{Min}, V_{IN} = 7.0\text{V}, V_{\text{CLOCK}} = 3.5\text{V}, V_{\text{OUT}} = 1.0\text{V}$	-7	-17	mA
I _{OS}	Output Short Circuit Current	$V_{CC} = \text{Max}, V_{IN} = 2.7\text{V}, V_{\text{CLOCK}} = 3.5\text{V}, V_{\text{OUT}} = 0\text{V}$		-1.2	mA
CLOCK INPUT					
I _{IN}	Input Current	$V_{IN} = 3.5\text{V}$		300	μA
		$V_{IN} = 1.6\text{V}$	50		μA
V _{IH}	Logical "1" Input High Voltage		3.5		V
V _{IL}	Logical "0" Input Low Voltage			1.6	V
MOTOR DRIVER					
I _{IN(PRINT)}	Input Current	$V_{IN} = 2.3\text{V}$	50		μA
		$V_{IN} = 9.5\text{V}$		250	μA
I _{IL(STOP)}	Input Low Current (Stop)	$V_{CC} = \text{Min}, V_{IN(\text{STOP})} = 0.4\text{V}$, (Stop Switch Closed)		-700	μA
V _{IH(STOP)}	Input High Voltage (Stop)	$V_{CC} = \text{Max}, I_{IN(\text{STOP})} = -10 \mu\text{A}$, (Stop Switch Open)		2.5	V
V _{OL}	Output Low Voltage	$V_{CC} = \text{Min}, V_{\text{PRINT}} = 7\text{V}, I_{\text{OUT}} = 15 \text{ mA}$		0.5	V

Electrical Characteristics (Continued) DS8693

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
MOTOR DRIVER (Continued)					
I _{OX}	Output Leakage Current	V _{CC} = Max, V _{PRINT} = 2.3V, V _{STOP} = 0.8V, V _{OUT} = 15V		100	μA
I _{IH(STOP)}	Logical "1" Input High Current			-10	μA
COLOR DRIVER					
I _{IN}	Input Current	V _{IN} = 3.5V		300	μA
		V _{IN} = 1.7V	50		μA
V _{OL}	Output OFF Voltage	V _{CC} = Min, V _{IN} = 1.7V, I _{OUT} = 1 mA		0.4	V
I _{OH}	Output ON Current	V _{CC} = Min, V _{IN} = 3.5V, V _{OUT} = 1.0V	-8	-18	mA
I _{CC(SB)}	Stand-by Supply Current, (Note 6)	V _{CC} = Max, V _{COLUMN IN/VPRINT} = 0V, V _{COLOR} = 0V, V _{CLOCK} = 3.5V		55	mA

Absolute Maximum Ratings DS8694 (Note 1)

Supply Voltage	12V
Input Voltage	
All Pins Except Pin 15	12V
Pin 15	19V
Output Voltage	12V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	2005 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions DS8694

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	8.5	11.0	V
Temperature (T _A)	0	+70	°C

*Derate molded package 16.04 mW/°C above 25°C.

Electrical Characteristics DS8694 (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
COLUMN DRIVER						
I _{IN}	Input Current	V _{IN} = 2.7V		50	μA	
		V _{IN} = 9.5V		250	μA	
V _{OL}	Output OFF Voltage	V _{CC} = Min, V _{IN} = 2.7V, V _{CLOCK} = 3.5V, I _{OUT} = 1 mA		0.4	V	
I _{OH}	Output ON Current	V _{CC} = Min, V _{IN} = 7.0V, V _{CLOCK} = 3.5V, V _{OUT} = 1.0V	-7	-17	mA	
I _{OS}	Output Short-Circuit Current	V _{CC} = Max, V _{IN} = 2.7V, V _{CLOCK} = 3.5V, V _{OUT} = 0V		-1.2	mA	
CLOCK INPUT						
I _{IN}	Input Current	V _{IN} = 3.5V		300	μA	
		V _{IN} = 2.7V	50		μA	
V _{IH}	Logical "1" Input High Voltage		3.5		V	
V _{IL}	Logical "0" Input Low Voltage			1.6	V	
TIMING BUFFER						
I _{IN}	Input Current	V _{IN} = 2V		-50	μA	
		V _{IN} = 17V		880	μA	
V _{OL}	Output Low Voltage	I _{OUT} = 50 μA, V _{IN} = 10V		0.5	V	
V _{OH}	Output High Voltage	I _{OUT} = -50 μA, V _{IN} = 7V	V _{CC} -1.0		V	
OSCILLATOR						
f _{OSC}	Frequency	V _{CC} = Max, R = 18k, C = 0.0015 μFd, (Note 5)	85	100	115	kHz
V _{OL}	Output Low Voltage	V _{CC} = Min, I _{OUT} = 50 μA		0.5	V	
V _{OH}	Output High Voltage	I _{OUT} = -50 μA	V _{CC} -1.0		V	
DC	Duty Cycle	V _{CC} = Max	40	50	60	%
V _{OSC}	Osc. V _{CC} Turn ON Voltage		6.0	7.7	8.5	V
I _{CC(SB)}	Stand-by Supply Current	V _{CC} = Max, V _{COLUMN IN/VPRINT} = 0V, I _{CLOCK} = 300 μA		55	mA	

Switching Characteristics DS8694

V_{CC} = 5V, T_A = 25°C (unless otherwise specified)

DS8692, DS8693, DS8694

5

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
COLUMN DRIVERS (DS8693, DS8694) (Figure 3)						
PWCOLUMN	Column In Pulse Width		1.1			μs
PWCLOCK	Clock Pulse Width		1.0			μs
t _d	Delay of Column In Pulse After Clock Transitions to Low State for Output to Latch		0.1			μs
t _{PD0}	Propagation Delay to a Logical "0" From Clock to Column Output	Column I _n = 0V			10.0	μs
t _{PD1}	Propagation Delay to a Logical "1" From Clock to Column Output	Column I _n = 7V			1300	μs
t _{PD0}	Propagation Delay to a Logical "0" From Column In to Column Out	Clock = 7V			10	μs
t _{PD1}	Propagation Delay to a Logical "1" From Column In to Column Out	Clock = 7V			1300	μs
COLOR DRIVER (DS8693) (Figure 4)						
t _{PD0}	Propagation Delay to a Logical "0" From Color In to Color Out				10.0	μs
t _{PD1}	Propagation Delay to a Logical "1" From Color In to Color Out				10.0	μs
MOTOR DRIVER (DS8693) (Figure 6)						
PWPRINT	Print Signal Pulse Width		1			μs
PWSTOP	Stop Signal Pulse Width		1			μs
PWCLOCK	Clock Pulse Width		1			μs
t _{PD0}	Propagation Delay to a Logical "0" From Print to Motor Drive Out				10	μs
t _{PD1}	Propagation Delay to a Logical "1" From Motor Stop (High-to-Low Transition) to Motor Drive Out	Print = 0V, Clock = 7.0V			10	μs
TIMING SIGNAL BUFFER (DS8694) (Figure 5)						
PWTIMING	Timing Signal Pulse Width		1	1000		ms
t _r	Rise Time	C _{LOAD} = 35 pF			500	ns
t _f	Fall Time	C _{LOAD} = 35 pF			500	ns
t _{PD0}	Propagation Delay to a Logical "0" From Timing In to Timing Out				10	μs
t _{PD1}	Propagation Delay to a Logical "1" From Timing In to Timing Out				10	μs
CLOCK OSCILLATOR (DS8694) (Figure 7)						
f _{OSC}	Oscillator Frequency	(Note 5)	85	100	115	kHz
DC	Duty Cycle		40	50	60	%
t _r	Rise Time	C _{LOAD} = 70 pF			500	ns
t _f	Fall Time	C _{LOAD} = 70 pF			500	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS8692, DS8693, DS8694. All typicals are given for V_{CC} = 10V and T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute basis.

Note 4: Ratings refer to a high current point where collector-emitter voltage is lowest.

Note 5: Oscillator frequency is determined by external R between "Osc R" and "Osc C" and external C from "Osc C" to ground. 2k > R > 20k.

Note 6: Column outputs operate on approximately 1/16 duty cycle in normal operation.

Note 7: Measured with one output on at a time.

System Connection Diagram

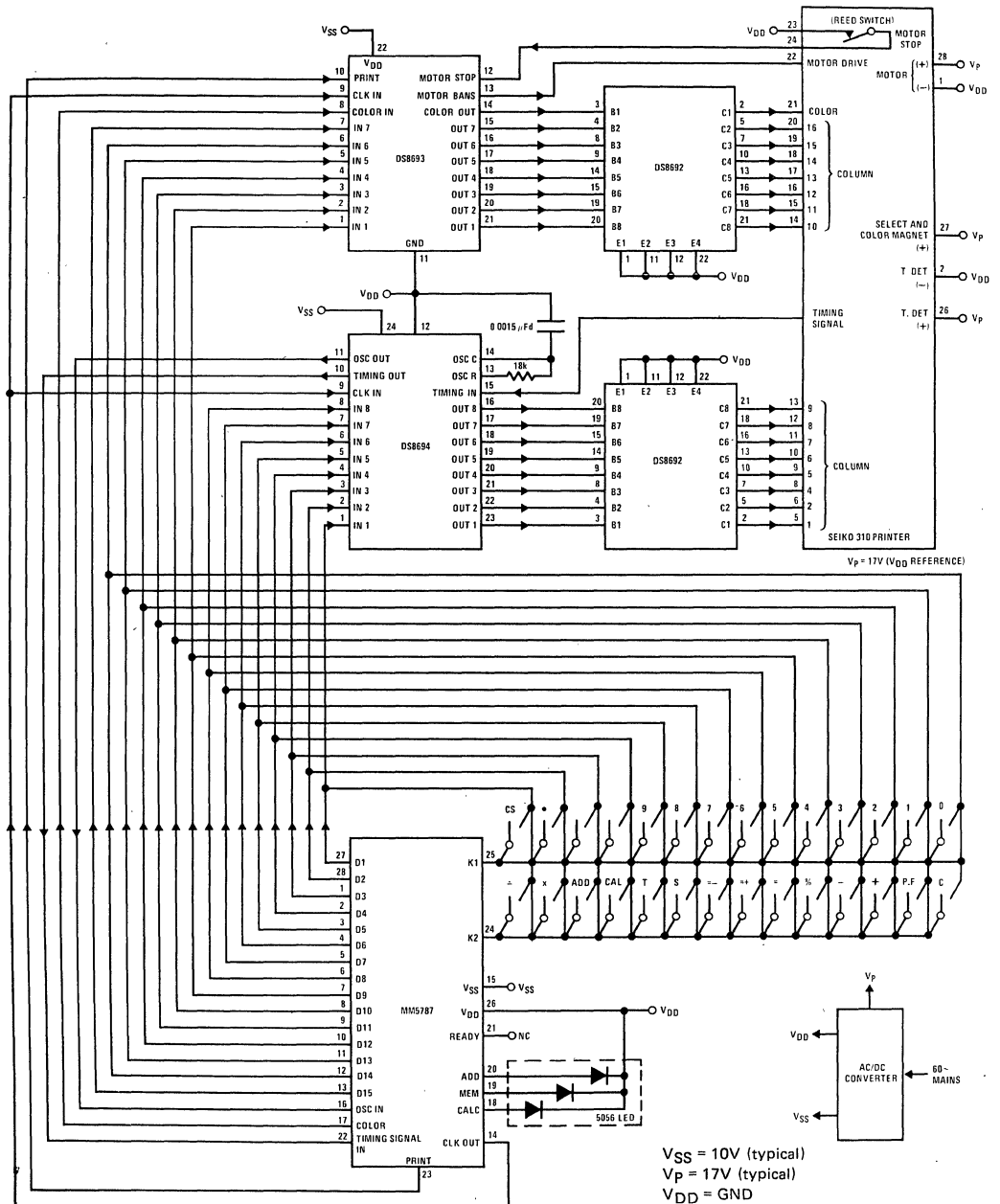
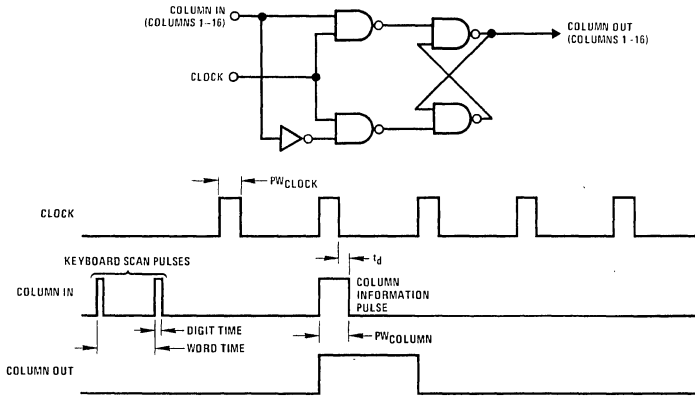


FIGURE 1

Logic and Timing Diagrams



Switching Time Waveforms

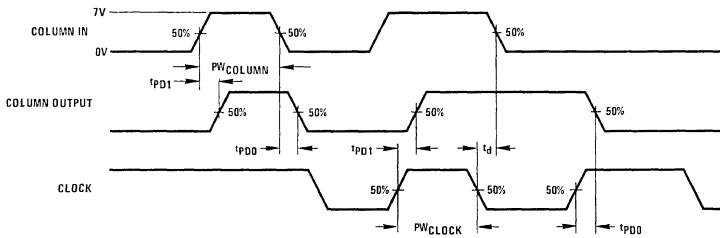


FIGURE 3. DS8693, DS8694 Column Latch

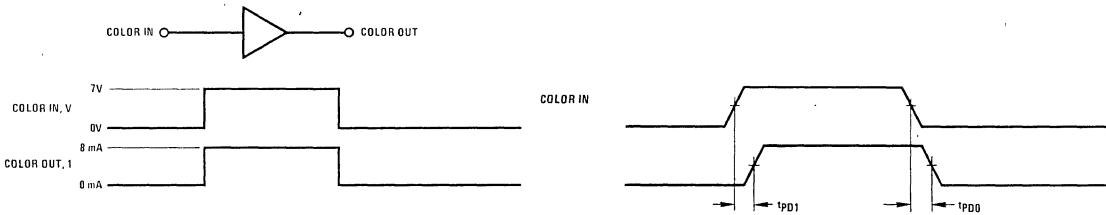


FIGURE 4. DS8693 Color Driver

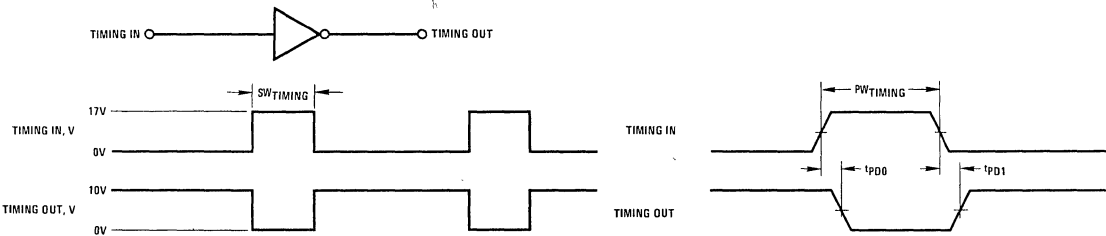
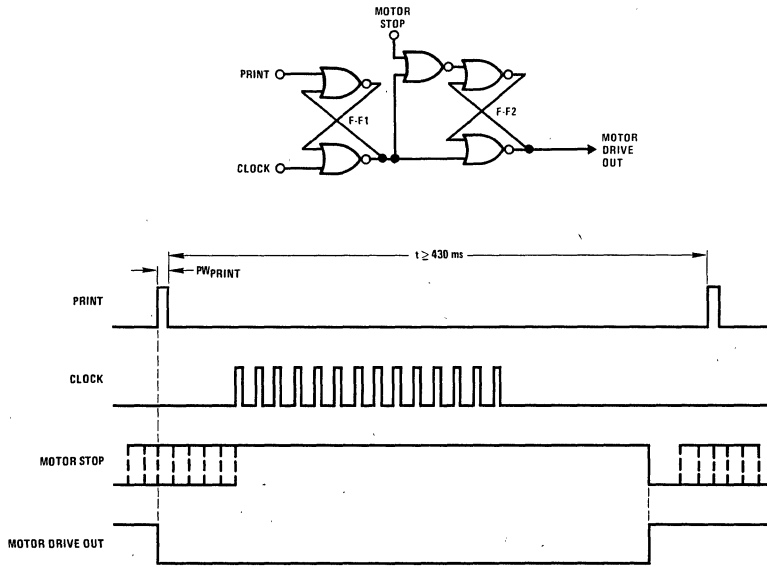


FIGURE 5. DS8694 Timing Signal Buffer

Logic and Timing Diagrams



Switching Time Waveforms

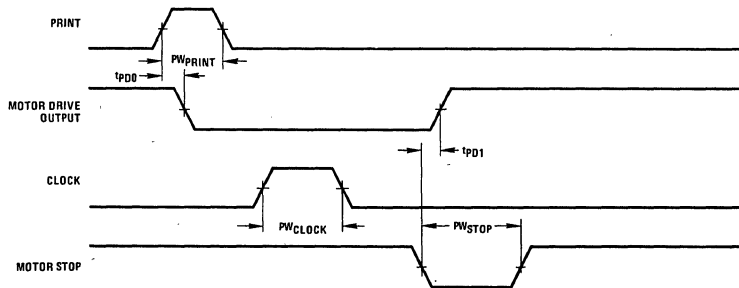


FIGURE 6. DS8693 Motor Drive Latch

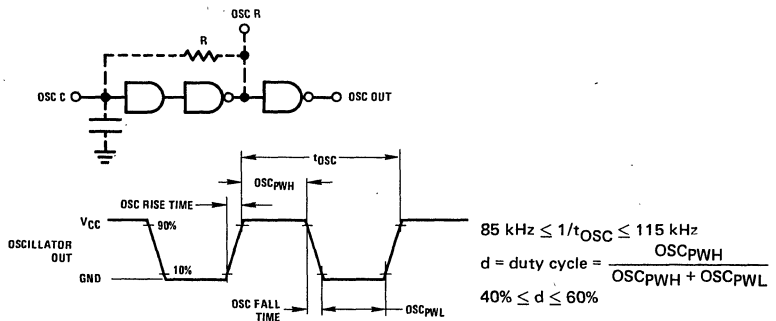


FIGURE 7. DS8694 Oscillator Diagram

DS8859A, DS8869A Open Collector Hex Latch LED Drivers

General Description

The DS8859A, DS8869A are TTL compatible open collector hex latch LED drivers with programmable current sink outputs. The current sinks are nominally set at 14 mA but may be adjusted by external resistors for any value between 0–32 mA. Each device contains six latches which may be set by input data terminals. An active low strobe common to all six latches enables the data input terminals. The DS8859A current sink outputs are switched on by entering a high level into the latches and the DS8869A current sink outputs are switched on by entering a low level into the latches.

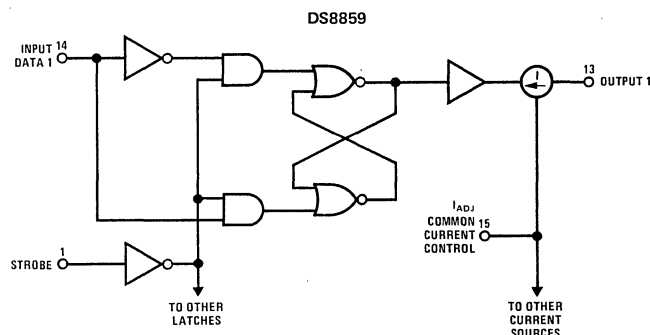
The devices are available in either a molded or cavity package. In order not to damage the devices there is a

limit placed on the power dissipation allowable for each package type. This information is shown in the graph included in this data sheet.

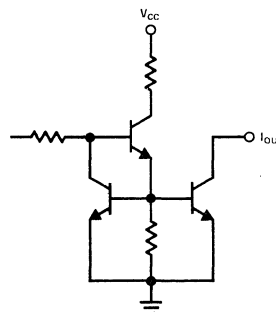
Features

- Built-in latch
- Programmable output current
- TTL compatible inputs
- 32 mA output sink

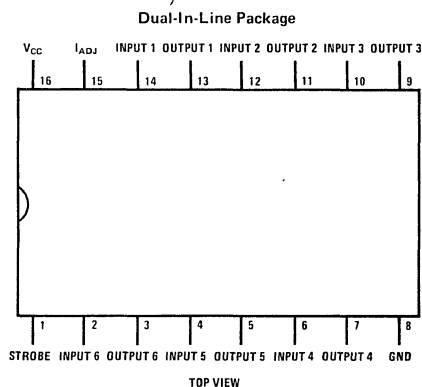
Logic Diagram



Output Circuit



Connection Diagram



Truth Table

COMMON STROBE	INPUT DATA	DS8859 OUTPUT (t + 1)	DS8869 OUTPUT (t + 1)
0	0	OFF	ON
0	1	ON	OFF
1	X	OUTPUT (t)	OUTPUT (t)

Order Number DS8859AJ, DS8869AJ,
DS8859AN or DS8869AN
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.55 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V _{CC}	4.75	5.25	V
Temperature, T _A	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{IH} Logical "1" Input Voltage	V _{CC} = Min	2.0			V
I _{IH} Logical "1" Input Current	V _{CC} = Max, V _{IN} = 2.4V			40	μA
V _{IL} Logical "0" Input Voltage	V _{CC} = Min			0.8	V
I _{IL} Logical "0" Input Current	V _{CC} = Max, V _{IN} = 0.4V		-1.0	-1.6	mA
V _{CD} Input Clamp Voltage	V _{CC} = Min, I _{IN} = -12 mA		-1.1	-1.5	V
I _{OH} Logical "1" Output Current	V _{CC} = Min, V _{IL} = 0.8V, V _{OH} = 5.5V, V _{IH} = 2.0V			250	μA
V _{OL} Logical "0" Output Voltage	V _{CC} = Min, V _{IL} = 0.8V, I _{OL} = 16 mA, V _{IH} = 2V, V _{IADJ} = V _{CCMIN}			0.4	V
I _{CC} Supply Current	V _{CC} = Max, Current Sources "OFF," (See Truth Table), (Note 4)			50	mA
I _{SINK} Output Current	V _{CC} = 5.0V, V _{OUT} = 2.0V, T _A = 25°C, (Note 4)	V _{IADJ} = 5V	32		mA
		I _{ADJ} = Open	9	14	26

Switching Characteristics T_A = 25°C, V_{CC} = 5V

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t _{pdo} Propagation Delay to a Logical "0"	C _{OUT} = 15 pF, R _L = 390Ω, (Note 5)	Data to Output			36	ns
		Strobe to Output			50	ns
t _{pd1} Propagation Delay to a Logical "1"	C _{OUT} = 15 pF, R _L = 390Ω, (Note 5)	Data to Output			150	ns
		Strobe to Output			150	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

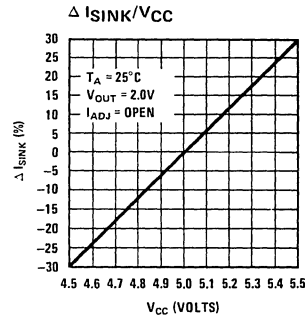
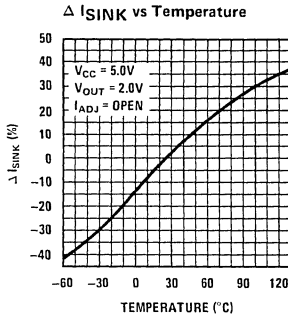
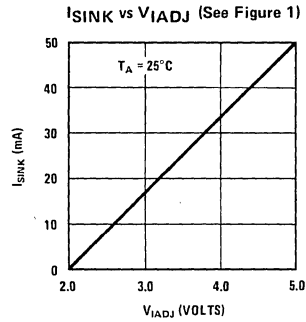
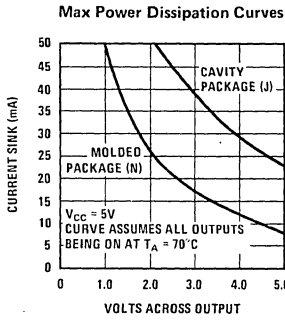
Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C temperature range. All typicals are given for V_{CC} = 5.0V and T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

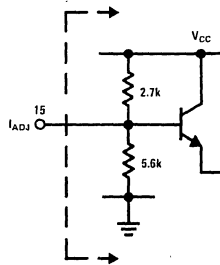
Note 4: See graphs for changes in I_{SINK} versus changes in temperature and V_{CC}.

Note 5: C_{OUT} includes device output capacitance of approximately 8.5 pF and wiring capacitance.

Typical Performance Characteristics



I_{SINK} Adjustment Circuit



I_{ADJ} may be programmed by a voltage source or by resistors.

FIGURE 1.

DS8861 MOS-to-LED 5-Segment Driver
DS8863 MOS-to-LED 8-Digit Driver
DS8963 MOS-to-LED 8-Digit Driver

General Description

The DS8861, DS8863 and DS8963 are designed to be used in conjunction with MOS integrated circuits and common-cathode LED's in serially addressed multi-digit displays.

The DS8861 is a 5-segment driver capable of sinking or sourcing up to 50 mA from each driver.

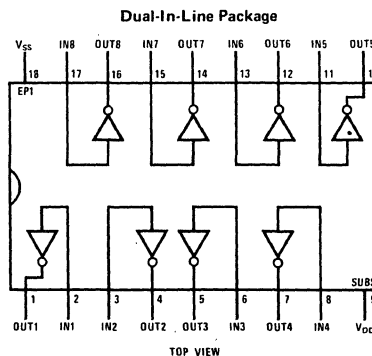
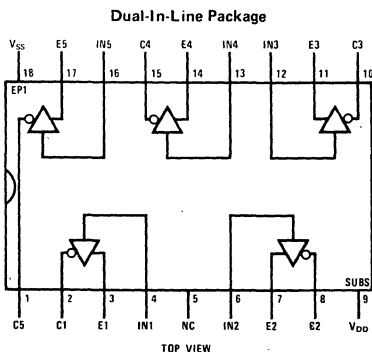
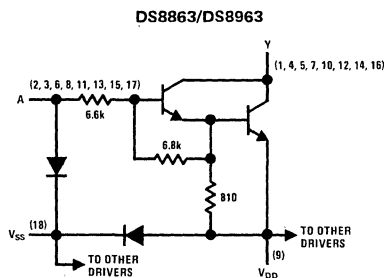
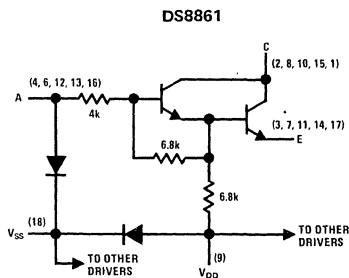
The DS8863 is an 8-digit driver. Each driver is capable of sinking up to 500 mA.

The DS8963 is identical to the DS8863 except it is intended for operation at up to 18V.

Features

- 50 mA source or sink capability per driver, DS8861
- 500 mA sink capability per driver, DS8863, DS8963
- MOS compatibility (low input current)
- Low standby power
- High gain Darlington circuits

Schematic and Connection Diagrams



Order Numbers DS8861N, DS8863N or DS8963N
 See NS Package N18A

Absolute Maximum Ratings

	DS8861	DS8863	DS8963
Input Voltage Range (Note 1)	-5V to V_{SS}	-5V to V_{SS}	-5V to V_{SS}
Collector (Output) Voltage (Note 2)	10V	10V	18V
Collector (Output)-to-Input Voltage	10V	10V	18V
Emitter-to-Ground Voltage ($V_I \geq 5V$)	10V		
Emitter-to-Input Voltage	5V		
Voltage at V_{SS} Terminal With Respect to Any Other Device Terminal	10V	10V	18V
Collector (Output) Current			
Each Collector (Output)	50 mA	500 mA	500 mA
All Collectors (Output)	200 mA	600 mA	600 mA
Continuous Total Dissipation	800 mW	800 mW	800 mW
Operating Temperature Range	0°C to +70°C	0°C to +70°C	0°C to +70°C
Storage Temperature Range	-65°C to +150°C	-65°C to +150°C	-65°C to +150°C
Maximum Power Dissipation at 25°C			
Molded Package	1476 mW*	1563 mW†	1563 mW†
Lead Temperature (Soldering, 10 sec)	300°C	300°C	300°C

*Derate molded package 11.81 mW/°C above 25°C.

†Derate molded package 12.5 mW/°C above 25°C.

Electrical Characteristics DS8861 ($V_{SS} = 10V$, $T_A = 0^\circ C$ to +70°C unless otherwise noted)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V_{CEON} "ON" State Collector Emitter Voltage	Input = 8V through 1 k Ω , $V_E = 5V$, $T_A = 25^\circ C$		0.9	1.2	V	
	$I_C = 50$ mA			1.5	V	
I_{COFF} "OFF" State Collector Current	$V_C = 10V$, $V_E = 0$	$I_{IN} = 40\mu A$			100	μA
		$V_{IN} = 0.7V$			100	μA
I_I Input Current at Maximum Input Voltage	$V_{IN} = 10V$, $V_E = 0$, $I_C = 20$ mA		2.2	3.3	mA	
I_E Emitter Reverse Current	$V_{IN} = 0$, $V_E = 5V$, $I_C = 0$			100	μA	
I_{SS} Current Into V_{SS} Terminal				1	mA	

DS8863/DS8963 ($V_{SS} = 10V$, $T_A = 0^\circ C$ to +70°C unless otherwise noted)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V_{OL} Low Level Output Voltage	$V_{IN} = 7V$, $I_{OUT} = 500$ mA, $T_A = 25^\circ C$			1.5	V	
				1.6	V	
I_{OH} High Level Output Current	$V_{OH} = 10V^*$	$I_{IN} = 40\mu A$			250	μA
		$V_{IN} = 0.5V$			250	μA
I_I Input Current at Maximum Input Voltage	$V_{IN} = 10V$, $I_{OL} = 20$ mA			2	mA	
I_{SS} Current Into V_{SS} Terminal				1	mA	

*18V for the DS8963

Switching Characteristics DS8861 ($V_{SS} = 7.5V$, $T_A = 25^\circ C$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-to-High Level Output (Collector)	$V_{IH} = 4.5V$, $V_E = 0$ $R_L = 200\Omega$, $C_L = 15$ pF		100		ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output (Collector)			20		ns

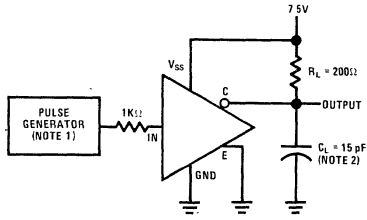
DS8863/DS8963 ($V_{SS} = 7.5V$, $T_A = 25^\circ C$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-to-High Level Output	$V_{IH} = 8V$, $R_L = 20\Omega$, $C_L = 15$ pF		300		ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output			30		ns

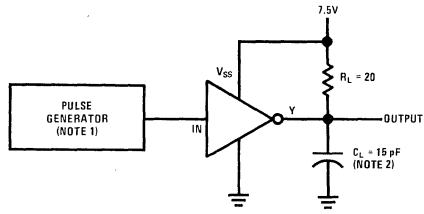
Note 1: The input is the only device terminal which may be negative with respect to ground.

Note 2: Voltage values are with respect to network ground terminal unless otherwise noted.

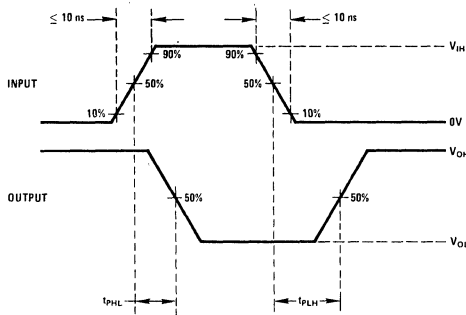
AC Test Circuits and Waveforms



DS8861



DS8863



NOTE 1: THE PULSE GENERATOR HAS THE FOLLOWING CHARACTERISTICS: $Z_{OUT} = 50\Omega$,
 PRR = 100 KHz, $t_W = 1\mu s$.
 NOTE 2: C_L INCLUDES PROBE AND JIG CAPACITANCE.

DS8867 8-Segment Constant Current Driver

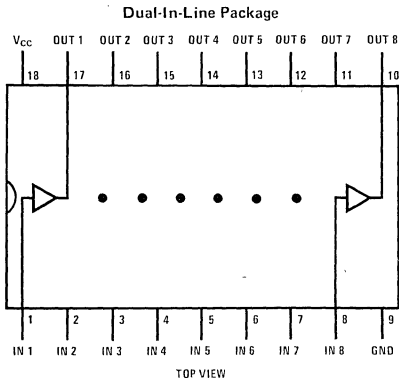
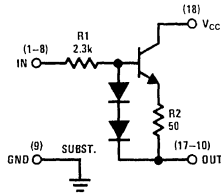
General Description

The DS8867 is an 8-segment driver designed to be driven from MOS circuits operating at $8V \pm 10\%$ minimum V_{SS} supply and will supply 14 mA typically to an LED display. The output current is insensitive to V_{CC} variations.

Features

- Internal current control—no external resistors
- 100% efficient, no standby power
- Operates in three and four cell battery systems
- Inputs and outputs grouped for easy PC layout

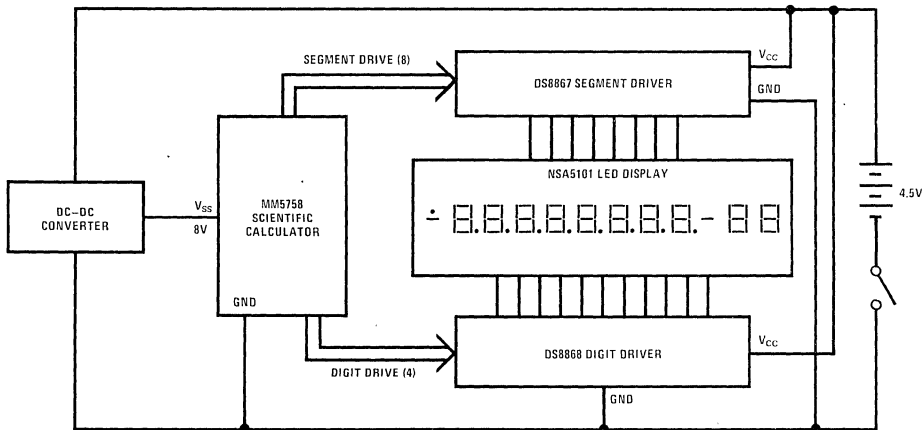
Schematic and Connection Diagrams



Order Number DS8867N
See NS Package N18A

Typical Application

Typical 3 Cell Scientific Calculator Circuit



Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	10V
Output Voltage	10V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1345 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 10.76 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC}	3.3	6.0	V
Temperature, T_A	0	+70	°C

Electrical Characteristics (Note 2)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	
V_{IH}	Logical "1" Input Voltage	$V_{CC} = \text{Min}, V_{OH} = 2.3V, I_{IH} = 500\mu A$		4.9	5.4	V	
I_{IL}	Logical "0" Input Current	$V_{CC} = \text{Max}, V_{OL} = 1.8V, V_{IL} = 2.0V$		0.1	10	μA	
I_{OH}	Logical "1" Output Current	$V_{CC} = \text{Min}, V_{OH} = 2.3V, I_{IH} = 500\mu A$	-8	-14	-18	mA	
I_{OL}	Logical "0" Output Current	$V_{CC} = \text{Max}, V_{OL} = 1.0V, V_{IL} = 1.3V$		-0.5	-10	μA	
$I_{CC \text{ OFF}}$	Supply Current	$V_{CC} = \text{Max}$	All $V_{OL} = 1.0V, V_{IL} = 1.3V, (\text{Standby})$		4	50	μA
$I_{CC \text{ ON}}$			All $V_{OH} = 2.3V, V_{IH} = 7.8V$		112	150	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C.

DS8870 Hex LED Digit Driver

General Description

The DS8870 is an interface circuit designed to be used in conjunction with MOS integrated circuits and common-cathode LED's in serially addressed multi-digit displays. The number of drivers required for this time-multiplexed system is minimized as a result of the segment-address-and-digit-scan method of LED drive.

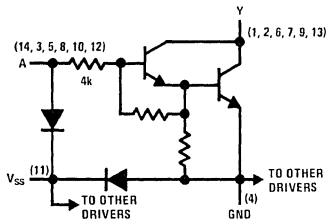
Features

- Sink capability per driver—350 mA
- MOS compatibility (low input current)
- Low standby power
- High-gain Darlington circuits

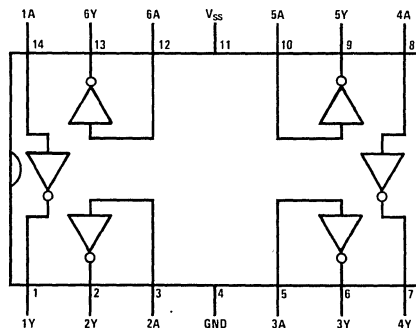
5

Schematic and Connection Diagrams

DS8870 (Each Driver)



Dual-In-Line Package



Order Number DS8870J or DS8870N
See NS Package J14A or N14A

Absolute Maximum Ratings (Note 1)

Input Voltage Range (Note 4)	-5V to V_{SS}
Collector Output Voltage	10V
Collector Output to Input Voltage	10V
Voltage at V_{SS} Terminal with Respect to Any Other Device Terminal	10V
Collector Output Current	
Each Collector Output	350 mA
All Collector Outputs	600 mA
Continuous Total Dissipation	800 mW
Operating Temperature Range	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1308 mW
Molded Package	1207 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 8.72 mW/°C above 25°C; derate molded package 9.66 mW/°C above 25°C.

Electrical Characteristics ($V_{SS} = 10V$) (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{OL} Low Level Output Voltage	Input = 6.5V through 1 k Ω , $I_{OUT} = 350$ mA, $T_A = 25^\circ\text{C}$		1.2	1.4	V
V_{OL} Low Level Output Voltage	Input = 6.5V through 1 k Ω , $I_{OUT} = 350$ mA			1.6	V
I_{OH} High Level Output Current	$V_{OH} = 10V$, $I_{IN} = 40\mu\text{A}$			200	μA
I_{OH} High Level Output Current	$V_{OH} = 10V$, $V_{IN} = 0.5V$			200	μA
I_I Input Current at Maximum Input Voltage	$V_{IN} = 10V$, $I_{OL} = 20$ mA		2.2	3.3	mA
I_{SS} Current Into V_{SS} Terminal				1	mA

Switching Characteristics ($V_{SS} = 7.5V$, $T_A = 25^\circ\text{C}$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-to-High Level Output	$V_{IH} = 7.5V$, $R_L = 39\Omega$, $C_L = 15$ pF		300		ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output	$V_{IH} = 7.5V$, $R_L = 39\Omega$, $C_L = 15$ pF		30		ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C temperature range.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: The input is the only device terminal which may be negative with respect to ground.

DS8871, DS8872, DS8873 Saturating LED Cathode Drivers

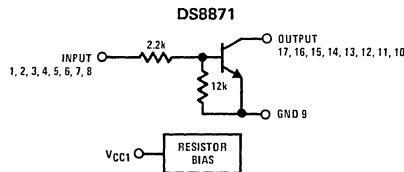
General Description

The DS8871, DS8872, and DS8873 are bipolar integrated circuits designed to interface between MOS calculator circuits and common cathode LED displays operating in the multiplexed mode with a digit current of up to 40 mA. The DS8871 is an 8-digit driver; the DS8872 is a 9-digit driver; and the DS8873 is a 9-digit driver with a built-in battery condition indicator that turns on the digit 9 decimal point when the battery voltage drops to 6.5V (typical). In a typical calculator system operating on a 9V battery, the low battery indicator comes on as a warning that the battery should be replaced. But the calculator (MM5737 or equivalent) will still function properly for awhile.

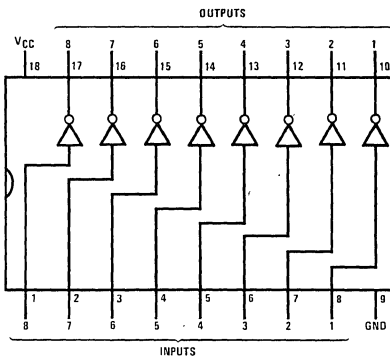
Features

- Single saturating transistor output
- Low battery indicator
- MOS compatible inputs
- Inputs and outputs clustered for easy wiring
- Drivers consume no standby power

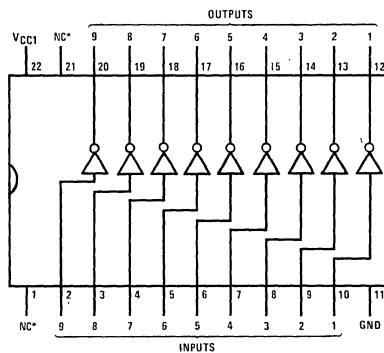
Schematic Diagram



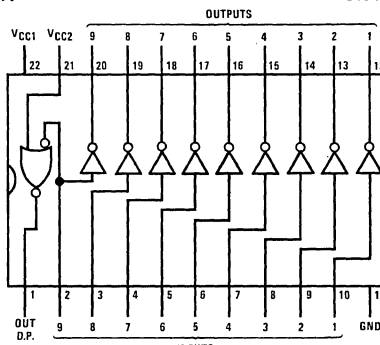
Connection Diagrams (Dual-In-Line Packages, Top Views)



Order Number **DS8871N**
See NS Package N18A



Order Number **DS8872N**
See NS Package N22A



Order Number **DS8873N**
See NS Package N22A

Absolute Maximum Ratings (Note 1)

Supply Voltage	$V_{CC1} = 11V$
Supply Voltage (Note 4)	$V_{CC2} = 11V$
Input Voltage	11V
Output Voltage	8V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation at 25°C	
Molded Package (DS8871)*	1563 mW
Molded Package (DS8872, DS8873)†	1771 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 12.5 mW/°C above 25°C.

†Derate molded package 14.17 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V_{CC1}	4.0	9.5	V
Supply Voltage, V_{CC2} (Note 4)	4.0	9.5	V
Temperature, T_A	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
I_{IL}	Logical "0" Input Current	$V_{IN} = 0.4V$	28	45	μA
I_{IH}	Logical "1" Input Current	$V_{IN} = 4.5V$	1.7	2.5	mA
V_{OL}	Logical "0" Output Voltage	$V_{IN} = 3.2V, I_{OL} = 40 mA$	0.35	0.5	V
I_{OL}	Logical "0" Output Current	$V_{IN} = 3.2V, V_{OL} = 0.5V$		40	mA
I_{CEX}	Output Leakage Current	$V_{OH} = 6V, I_{IN} = 25 \mu A$		40	μA
$I_{DP(ON)}$	Decimal Point Output Current	$V_{CC2} = 6.25V, V_{DP} = 2.5V, V_{IN9} = 3.2V,$ (Note 4)	-5.0	-7.0	mA
$I_{DP(OFF)}$	Decimal Point Output Current	$V_{CC2} = 7V, V_{IN9} = 3.2V, V_{DP} = 1V,$ (Note 4)	-1	-100	μA
I_{CC1}	Supply Current, V_{CC1}	$V_{CC1} = 6.5V, V_{IN} = 0V$	1	100	μA
I_{CC2}	Supply Current, V_{CC2}	$V_{CC2} = 9.5V, V_{IN9} = 4.5V, (Note 4)$	0.9	1.2	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Applies to DS8873 only.

Typical Applications

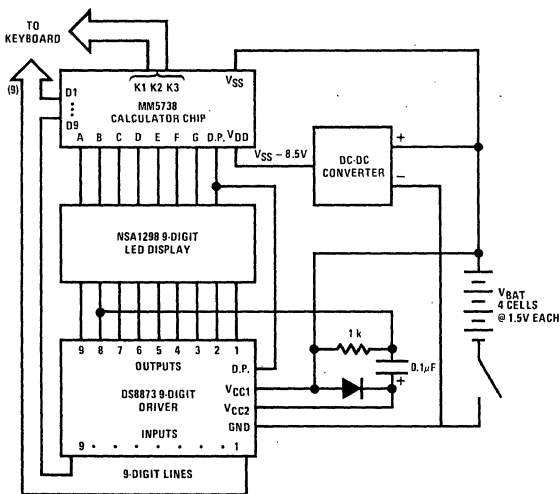


FIGURE 1. 4-Cell System

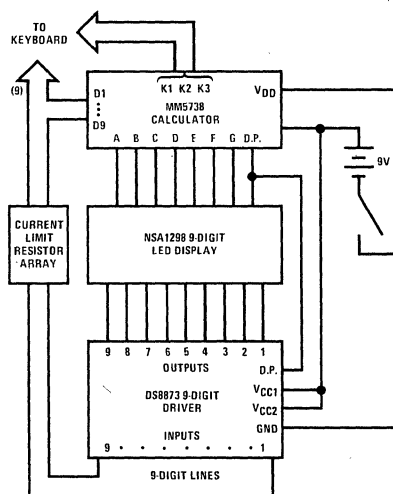


FIGURE 2. 9V System

DS8874 9-Digit Shift Input LED Driver

General Description

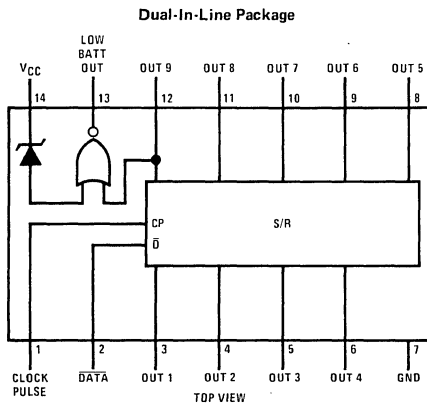
The DS8874 is a 9-digit LED driver which incorporates a shift register input decoding circuit and a low battery indicator. Outputs will sink 110 mA at less than 0.5V drop when sequentially selected. When the V_{CC} supply falls below 6.5V typical, segment current will be furnished at digit 9 time to indicate a low battery condition. Pin 13 is generally connected to the decimal point segment on the display so that when a low battery condition exists, the left-most decimal point lights up. The digit driver is intended to be used with the

MM5784N 5-function, 9-digit accumulating memory calculator circuit, or any other circuit which supplies the 9-digit information in a similar serial format.

Features

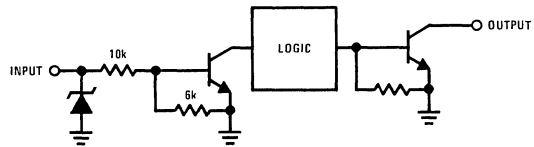
- 110 mA digit sink
- Low battery indicator
- Minimum number of connections
- MOS compatible inputs

Connection Diagram



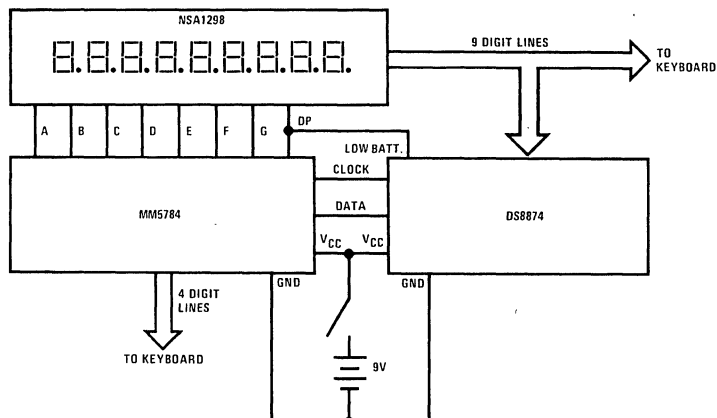
Order Number DS8874N
See NS Package N14A

Equivalent Schematic



Typical Application

Typical Application of the DS8874 Digit Driver with the MM5784 5-Function Calculator Circuit, NSA1298 9-Digit LED Display and a 9V Battery



Absolute Maximum Ratings (Note 1)

Supply Voltage	10V
Input Voltage	3V
Output Voltage	10V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1280 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 10.24 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	6.0	9.5	V
Temperature (T_A)	0	+70	°C

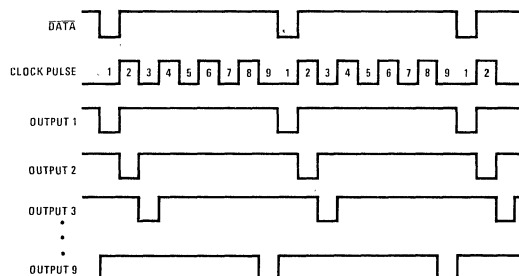
Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
I_{IH}	Logical "1" Input Current	$V_{CC} = \text{Max}, V_{IN} = 3V$		0.25	0.4	mA
I_{IL}	Logical "0" Input Current	$V_{CC} = \text{Max}, V_{IN} = 0.8V$		0.05	0.1	mA
V_{CCCL}	Decimal Point "ON"	$V_{dp} = 2.3V, I_{dp} = -4 \text{ mA}, O9 = V_{OL}$			6.0	V
V_{CCH}	Decimal Point "OFF"	$V_{dp} = 1V, I_{dp} = -10\mu A, O9 = V_{OL}$	7.0			V
I_{OH}	Logical "1" Output Current	$V_{CC} = \text{Max}, \text{Output Not Selected}$			100	μA
V_{OL}	Logical "0" Output Voltage	$V_{CC} = \text{Min}, \text{Output Selected}, I_{O1} = 80 \text{ mA}$		0.45	1	V
		$V_{CC} = \text{Max}, \text{Output Selected}, I_{O1} = 110 \text{ mA}$		0.6	1.5	V
I_{CC}	Supply Current	$V_{CC} = \text{Max}, \text{One Output Selected}$		13	19	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range. All typicals are given for $T_A = 25^\circ\text{C}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Timing Diagram (Upper Level More Positive)

DS8877 6-Digit LED Driver

General Description

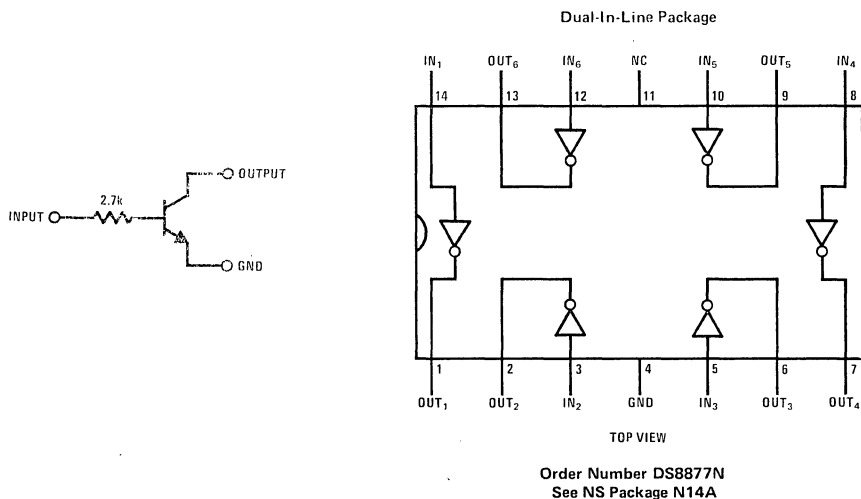
The DS8877 is a 6-digit LED driver designed as a pin-for-pin replacement for the DS75492 in applications where digit current is in the 5 to 50 mA range. Since the outputs saturate to less than 0.6V, the DS8877 will work on lower battery voltages than most digit drivers. The DS8877 draws *no* standby power.

Features

- No standby power
- No supply connection
- Operates in 4.5V, 6V or 9V systems
- Pin-for-pin replacement for DS75492 in low current applications

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Logic and Connection Diagrams



Absolute Maximum Ratings (Note 1)

Supply Voltage	None Required
Input Voltage	10V
Output Voltage	10V
Operating Temperature Range	0°C to +70°C
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1106 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 8.85 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

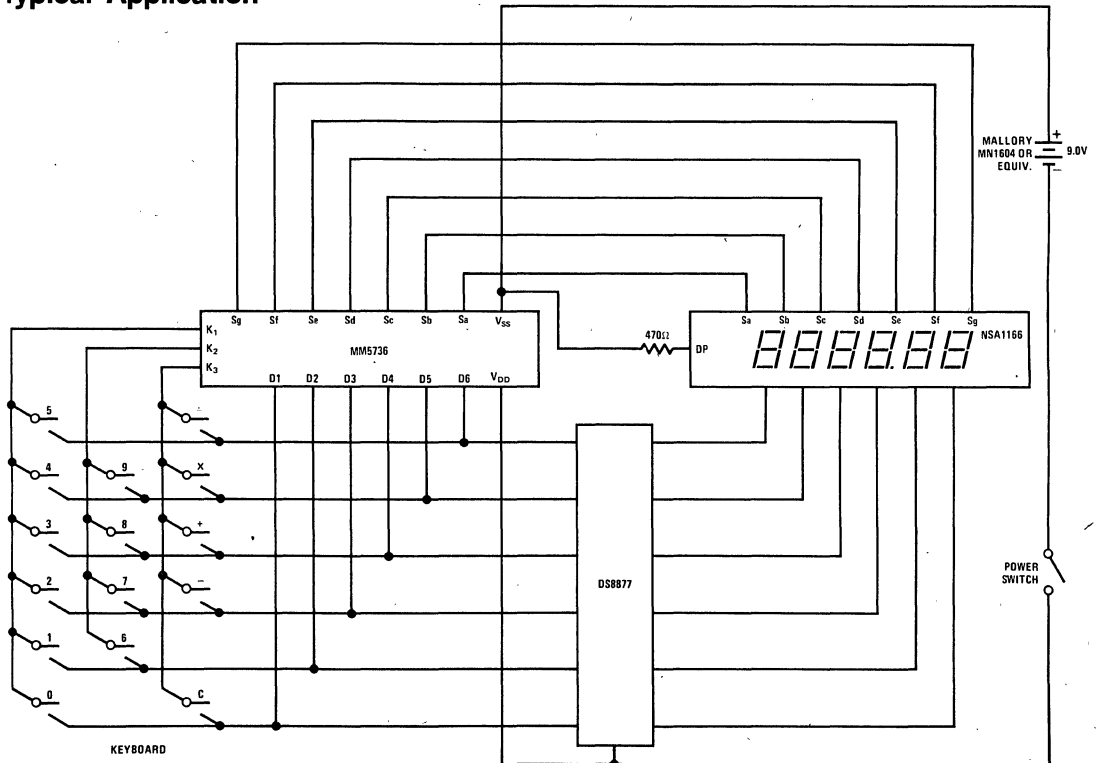
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{IH}	Logical "1" Input Voltage	5.0			V
I _{IH}	Logical "1" Input Current			1.2	mA
V _{IL}	Logical "0" Input Voltage			0.35	V
I _{IL}	Logical "0" Input Current			20	μA
I _{CEX}	Logical "1" Output Current			100	μA
V _{OL}	Logical "0" Output Voltage			0.5	V
I _{OL}	Logical "0" Output Current	35	50		mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range. All typicals are given for T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Typical Application



Calculator Configuration with MM5736 6-Digit Calculator

DS7880/DS8880 High Voltage 7-Segment Decoder/Driver

General Description

The DS7880/DS8880 is custom designed to decode four lines of BCD and drive a gas-filled seven-segment display tube.

Each output constitutes a switchable, adjustable current sink which provides constant current to the tube segment, even with high tube anode supply tolerance or fluctuation. These current sinks have a voltage compliance from 3V to at least 80V; typically the output current varies 1% for output voltage changes of 3 to 50V. Each bit line of the decoder switches a current sink on or off as prescribed by the input code. Each current sink is ratioed to the b-output current as required for even illumination of all segments.

Output currents may be varied over the 0.2 to 1.5 mA range for driving various tube types or multiplex operation. The output current is adjusted by connecting an external program resistor

(R_p) from V_{CC} to the Program input in accordance with the programming curve. The circuit design provides a one-to-one correlation between program input current and b-segment output current.

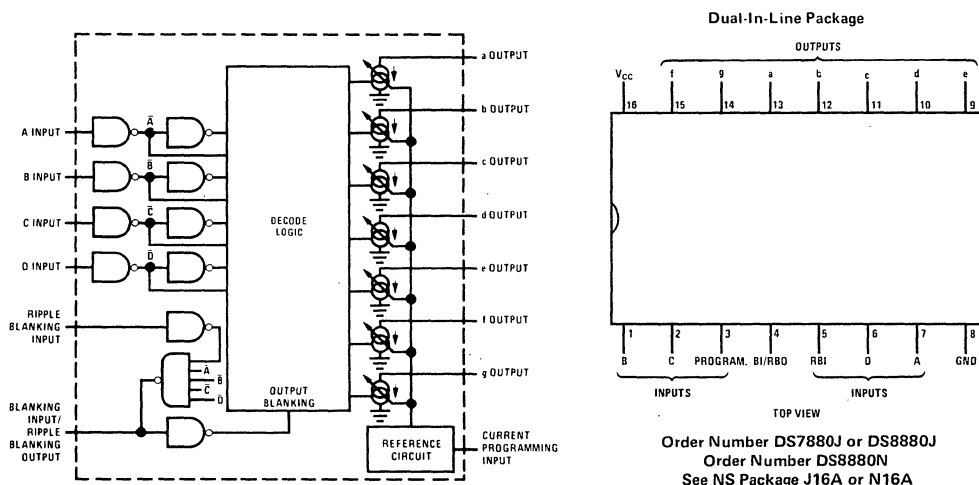
The Blanking Input provides unconditional blanking of any output display, while the Ripple Blanking pins allow simple leading- or trailing-zero blanking.

Features

- Current sink outputs
- Adjustable output current – 0.2 to 1.5 mA
- High output breakdown voltage – 110V typ
- Suitable for multiplex operation
- Blanking and Ripple Blanking provisions
- Low fan-in and low power

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Logic and Connection Diagrams



Absolute Maximum Ratings (Note 1)

V _{CC}	7V
Input Voltage (Except BI)	6V
Input Voltage (BI)	V _{CC}
Segment Output Voltage	80V
Power Dissipation	600 mW
Transient Segment Output Current (Note 4)	50 mA
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 sec)	300°C

*Derate cavity package 10.06 mW/°C above 25°C; derate molded package 11.81 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS7880	4.5	5.5	V
DS8880	4.75	5.25	V
Temperature (T _A)			
DS7880	-55	+125	°C
DS8880	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH}	Logical "1" Input Voltage	V _{CC} = Min	2.0			V	
V _{IL}	Logical "0" Input Voltage	V _{CC} = Min			0.8	V	
V _{OH}	Logical "1" Output Voltage	V _{CC} = Min, I _{OUT} = -200μA, R _{BO}	2.4	3.7		V	
V _{OL}	Logical "0" Output Voltage	V _{CC} = Min, I _{OUT} = 8 mA, R _{BO}		0.13	0.4	V	
I _{IH}	Logical "1" Input Current	V _{CC} = Max, Except BI	V _{IN} = 2.4V	2	15	μA	
			V _{IN} = 5.5V	4	400	μA	
I _{IL}	Logical "0" Input Current	V _{CC} = Max, V _{IN} = 0.4V	Except BI	-300	-600	μA	
			BI	-1.2	-2.0	mA	
I _{CC}	Power Supply Current	V _{CC} = Max, R _P = 2.2k, All Inputs = 0V		27	43	mA	
V _{CD}	Input Diode Clamp Voltage	V _{CC} = Max, T _A = 25°C, I _{IN} = -12 mA		-0.9	-1.5	V	
I _O	SEGMENT OUTPUTS "ON" Current Ratio	All Outputs = 50V, I _{OUTb} = Ref.	Outputs a, f, and g	0.84	0.93	1.02	
			Output c	1.12	1.25	1.38	
			Output d	0.90	1.00	1.10	
			Output e	0.99	1.10	1.21	
I _{b ON}	Output b "ON" Current	V _{CC} = 5V, V _{OUTb} = 50V, All Other Outputs ≥ 5V, T _A = 25°C	R _P = 18.1k	0.15	0.20	0.25	mA
			R _P = 7.03k	0.45	0.50	0.55	mA
			R _P = 3.40k	0.90	1.00	1.10	mA
			R _P = 2.20k	1.35	1.50	1.65	mA
V _{SAT}	Output Saturation Voltage	V _{CC} = Min, R _P = 1k±5%, I _{OUTb} = 2 mA, (Note 5)		0.8	2.5	V	
I _{CEX}	Output Leakage Current	V _{OUT} = 75V, BI = 0V, R _P = 2.2k		0.003	3	μA	
V _{BR}	Output Breakdown Voltage	I _{OUT} = 250μA, BI = 0V, R _P = 2.2k	80	110		V	
t _{pd}	Propagation Delays	V _{CC} = 5V, T _A = 25°C	BCD Input to Segment Output		0.4	10	μs
			BI to Segment Output		0.4	10	μs
			RBI to Segment Output		0.7	10	μs
			RBI to RBO		0.4	10	μs

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

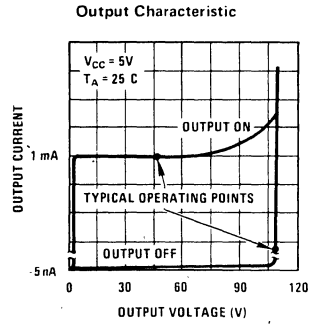
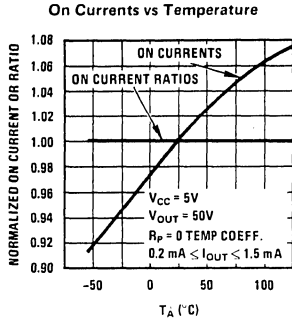
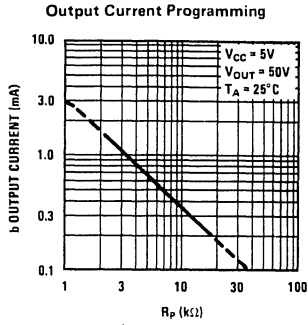
Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS7880 and across the 0°C to +70°C range for the DS8880. All typical values are for T_A = 25°C and V_{CC} = 5V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

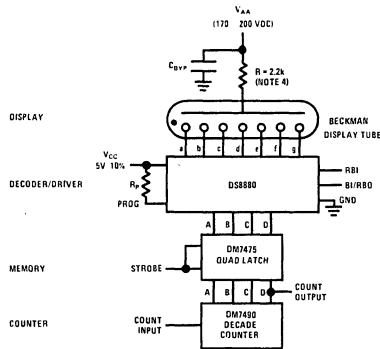
Note 4: In all applications transient segment output current must be limited to 50 mA. This may be accomplished in dc applications by connecting a 2.2k resistor from the anode-supply filter capacitor to the display anode, or by current limiting the anode driver in multiplex applications.

Note 5: For saturation mode the segment output currents are externally limited and ratioed.

Typical Performance Characteristics



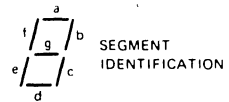
Typical Application



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Truth Table

DECIMAL OR FUNCTION	RBI†	D	C	B	A	BI/RBO	a	b	c	d	e	f	g	DISPLAY
0	1	0	0	0	0	1	0	0	0	0	0	0	1	0
1	X	0	0	0	1	1	1	0	0	1	1	1	1	1
2	X	0	0	1	0	1	0	0	1	0	0	1	0	2
3	X	0	0	1	1	1	0	0	0	0	1	1	0	3
4	X	0	1	0	0	1	1	0	0	1	1	0	0	4
5	X	0	1	0	1	1	0	1	0	0	1	0	0	5
6	X	0	1	1	0	1	0	1	0	0	0	0	0	6
7	X	0	1	1	1	1	0	0	0	1	1	1	1	7
8	X	1	0	0	0	1	0	0	0	0	0	0	0	8
9	X	1	0	0	1	1	0	0	0	0	1	0	0	9
10	X	1	0	1	0	1	0	0	0	1	0	0	0	10
11	X	1	0	1	1	1	1	1	0	0	0	0	0	11
12	X	1	1	0	0	1	0	1	1	0	0	0	1	12
13	X	1	1	0	1	1	1	0	0	0	0	1	0	13
14	X	1	1	1	0	1	0	1	1	0	0	0	0	14
15	X	1	1	1	1	1	0	1	1	1	0	0	0	15
BI*	X	X	X	X	X	0*	1	1	1	1	1	1	1	BI
RBI	0	0	0	0	0	0	1	1	1	1	1	1	1	RBI



*BI/RBO used as input only

†X = Don't care

DS8881 Vacuum Fluorescent Display Driver

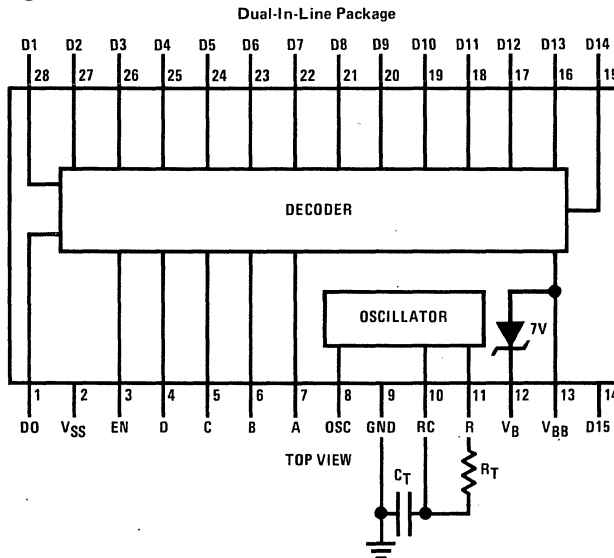
General Description

The DS8881 vacuum fluorescent display driver will drive 16-digit grids of a vacuum fluorescent display. The decode inputs select one of the sixteen outputs to be pulled high. The device contains an oscillator for supplying clock signals to the MOS circuit, the filament bias zener and 50 kΩ pull-down resistors for each grid. Outputs will source up to 7 mA. The DS8881 is designed for 9V operation. If the enable input is pulled low, all outputs are disabled.

Features

- Oscillator frequency accuracy and stability allows maximum system speed
- Interdigit blanking with the enable input provides ghost-free display operation
- 50 kΩ pull-down resistors for each grid
- 7V filament bias zener

Connection Diagram



Truth Table All outputs not shown high are off (low)

INPUTS					DIGIT OUTPUTS															
EN	D	C	B	A	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
H	L	L	L	L	H															
H	L	L	L	H		H														
H	L	L	H	L			H													
H	L	L	H	H				H												
H	L	H	L	H					H											
H	L	H	H	L						H										
H	L	H	H	H							H									
H	H	L	L	L								H								
H	H	L	L	H									H							
H	H	L	H	H										H						
H	H	H	L	L											H					
H	H	H	L	H												H				
H	H	L	H	H													H			
H	H	H	L	L														H		
H	H	H	H	L															H	
H	H	H	H	H																H
L	X	X	X	X		L	L	L	L	L	L	L	L	L	L	L	L	L	L	L

Absolute Maximum Ratings (Note 1)

Supply Voltage ($V_{SS} - V_{BB}$)	38V
Input Current	10 mA
Output Current	-20 mA
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	2168 mW
Lead Temperature (Soldering, 10 seconds)	300°C
*Derate molded package 17.35 mW/°C above 25°C.	

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage			
V_{SS}	5.0	9.5	V
V_{BB}	Gnd	-26	V
Temperature (T_A)	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS			MIN	TYP	MAX	UNITS
V_{IH}	Logical "1" Input Voltage	$V_{SS} = \text{Max}$	Enable	$I_{IN} = 260 \mu\text{A}$			5.1	V
			A, B, C, D	$I_{IN} = 1400 \mu\text{A}$			1.5	V
I_{IH}	Logical "1" Input Current	$V_{SS} = \text{Max}$	Enable A, B, C, D				260	μA
V_{IL}	Logical "0" Input Voltage	$V_{SS} = \text{Max}$	Enable				1.0	V
			A, B, C, D				0.3	V
I_{IL}	Logical "0" Input Current	$V_{SS} = \text{Max}$	Enable	$V_{IN} = 0\text{V}$			-1.0	μA
			A, B, C, D	$V_{IN} = V_{IL}(\text{MAX})$	25			μA
V_{OH}	Logical "1" Output Voltage	Digit Output, $I_{OH} = -7 \text{ mA}$			$V_{SS}-2.5$			V
I_{OH}	Logical "1" Output Current	$V_{SS} = \text{Max}$, Osc. Output, $V_{RC} = 0.6\text{V}$, $V_{OH} = 10\text{V}$					50	μA
I_{OS}	Output Short-Circuit Current	$V_{SS} = \text{Min}$, Pin R, $V_{RC} = 0.6\text{V}$, $V_R = 0\text{V}$			-150		-450	μA
R_{OUT}	Output Pull-Down Resistor	$V_{SS} = \text{Min}$, Digit Output			30	50	85	k Ω
V_{OL}	Logical "0" Output Voltage	$V_{SS} = \text{Min}$	Osc. Pin R	$V_{RC} = 1.6\text{V}$	$I_{OL} = 6 \text{ mA}$		0.5	V
					$I_{OL} = 60 \mu\text{A}$		0.2	V
		$V_{SS} = \text{Max}$	Digit Output	$V_{ENABLE} = 1\text{V}$	$I_{OL} = 10 \mu\text{A}$			$V_{BB}+1.4$
I_{SS}	Supply Current	$V_{SS} = 9.5\text{V}$	$I_{OH} = 0$	$V_{ENABLE} = 5.1\text{V}$		9.0	12.5	mA
				$V_{ENABLE} = 1\text{V}$		5.0	9.0	mA
I_{BB}	Supply Current	$V_{SS} = 9.5\text{V}$, $V_{BB} = -26\text{V}$	$I_B = 0$, $I_{IN} = 300 \mu\text{A}$, (Note 4)	$V_{ENABLE} = 1\text{V}$		-0.8	-1.5	mA
				$V_{ENABLE} = 5.1\text{V}$		-3.0	-5.0	mA
V_B	Filament Bias Voltage	$I_B = 10 \text{ mA}$			$V_{BB}+6.4$	$V_{BB}+6.9$	$V_{BB}+7.4$	V

Switching Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified.

PARAMETER		CONDITIONS			MIN	TYP	MAX	UNITS	
t_{pd0}	Propagation Delay to a Logical "0" From Enable Input to Digit Output	$R_L' = 4.7 \text{ k}\Omega$, $C_L' = 50 \text{ pF}$, $V_{BB} = -23\text{V}$, $V_{SS} = 8\text{V}$					1	μs	
t_{pd0}	Propagation Delay to a Logical "0" A, B, C, D to Digit Output						1	μs	
t_{pd1}	Propagation Delay to a Logical "1" From Enable Input to Digit Output							300	ns
t_{pd1}	Propagation Delay to a Logical "1" From A, B, C, D to Digit Output							500	ns
t_{FALL}	Oscillator Output Transition Time From 1 to 0	$V_{SS} = 9.5\text{V}$, $R_L = 6\text{k}$ to V_{SS} , $C_L = 25 \text{ pF}$					50	ns	
f_{OSC}	Oscillator Frequency	$7\text{V} < V_{SS} < 9.5\text{V}$, $R_T = 27 \text{ k}\Omega, \pm 2\%$, $R_L = 1.3\text{k}$,			320	360	400	kHz	
dc	Oscillator Duty Cycle	$C_T = 100 \text{ pF} \pm 5\%$, $C_L = 50 \text{ pF}$			46	56	66	%	

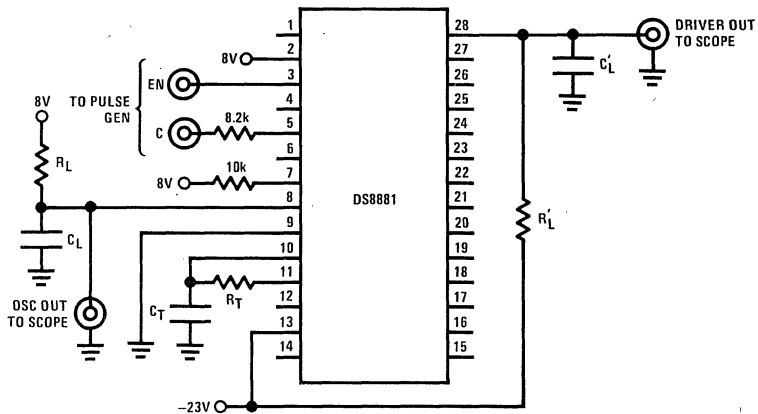
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C for the DS8881. All typicals are given for $V_{CC} = 5\text{V}$ and $T_A = 25^\circ\text{C}$.

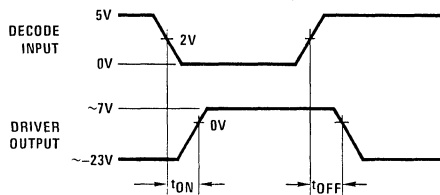
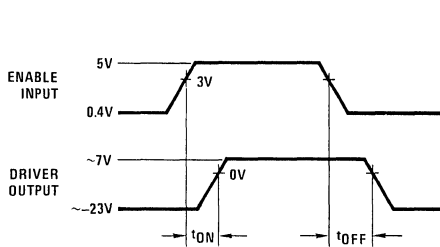
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Approximately 50% of input current on pins 4, 5, 6, 7 is shunted to V_{BB} . If minimum I_{BB} is desired, then I_{IN} should be minimized by using resistors in series with the inputs.

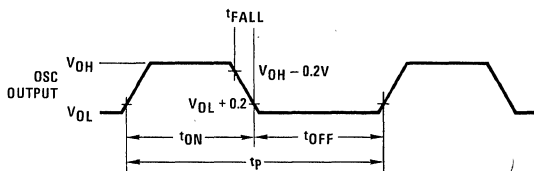
AC Test Circuit



Switching Time Waveforms



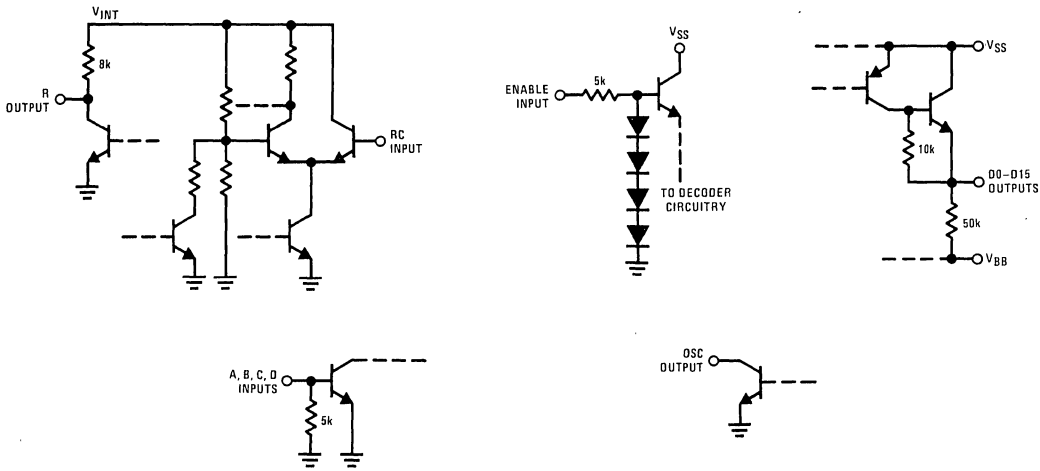
($t_r = t_f = 10$ ns from 10% to 90% of input)



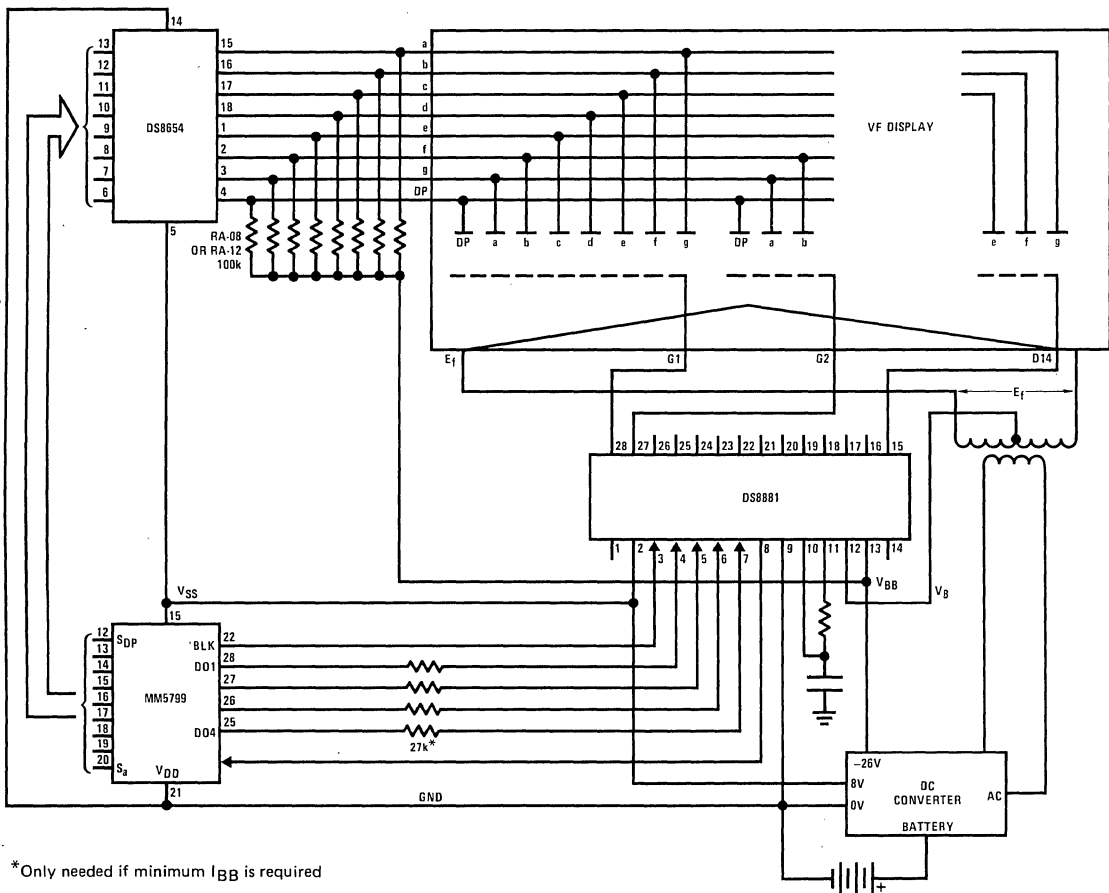
$$\text{Duty Cycle} = \frac{t_{ON}}{t_p}$$

$$\text{Frequency} = \frac{1}{t_p}$$

Input-Output Schematics



Typical Application



*Only needed if minimum I_{BB} is required

DS8884A High Voltage Cathode Decoder/Driver

General Description

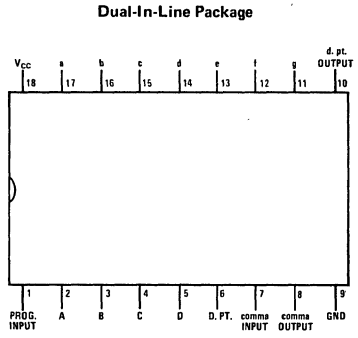
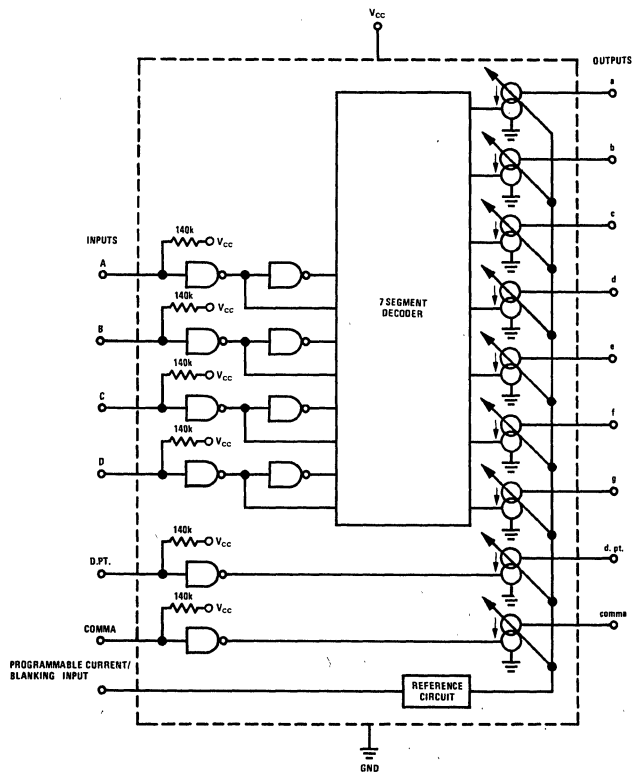
The DS8884A is designed to decode four lines of BCD input and drive seven-segment digits of gas-filled readout displays.

All outputs consist of switchable and programmable current sinks which provide constant current to the tube cathodes, even with high tube anode supply tolerance. Output currents may be varied over the 0.2 to 1.2 mA range for multiplex operation. The output current is adjusted by connecting an external program resistor (R_p) from V_{CC} to the program input in accordance with the programming curve. Unused outputs must be tied to V_{CC} .

Features

- Usable with AC or DC input coupling
- Current sink outputs
- High output breakdown voltage
- Low input load current
- Intended for multiplex operation.
- Input pullups increase noise immunity
- Comma/d.pt. drive

Logic and Connection Diagrams



Order Number DS8884AN
See NS Package N18A

Absolute Maximum Ratings (Note 1)

V _{CC}	7V
Input Voltage (Note 4)	V _{CC}
Segment Output Voltage	80V
Power Dissipation	600 mW
Transient Segment Output Current (Note 5)	50 mA
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1714 mW

*Derate molded package 13.71 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	4.75	5.25	V
Temperature (T _A)	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	MAX	UNITS		
V _{IH}	Logical "1" Input Voltage	V _{CC} = 4.75V	2.0	V		
V _{IL}	Logical "0" Input Voltage	V _{CC} = 4.75V	1.0	V		
I _{IH}	Logical "1" Input Current	V _{CC} = 5.25V, V _{IN} = 2.4V	15	μA		
I _{IL}	Logical "0" Input Current	V _{CC} = 5.25V, V _{IN} = 0.4V	-250	μA		
I _{CC}	Power Supply Current	V _{CC} = 5.25V, R _P = 2.8k, All Inputs = 5V	40	mA		
V _{I+}	Positive Input Clamp Voltage	V _{CC} = 4.75V, I _{IN} = 1 mA	5.0	V		
V _{I-}	Negative Input Clamp Voltage	V _{CC} = 5V, I _{IN} = -12 mA, T _A = 25°C	-1.5	V		
SEGMENT OUTPUTS						
ΔI _O	"ON" Current Ratio	All Outputs = 50V, I _{OUT} b = Ref., All Outputs	0.9	1.1		
I _{b ON}	Output b "ON" Current	V _{CC} = 5V, V _{OUT} b = 50V, T _A = 25°C	R _P = 18.1k	0.15	0.25	mA
			R _P = 7.03k	0.45	0.55	mA
			R _P = 3.40k	0.90	1.10	mA
			R _P = 2.80k	1.08	1.32	mA
I _{C EX}	Output Leakage Current	V _{OUT} = 75V		5	μA	
V _{BR}	Output Breakdown Voltage	I _{OUT} = 250μA	80		V	
t _{pd}	Propagation Delay of Any Input to Segment Output	V _{CC} = 5V, T _A = 25°C		10	μs	

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Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C temperature range for the DS8884A. All typical values are for T_A = 25°C and V_{CC} = 5V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: This limit can be higher for a current limiting voltage source.

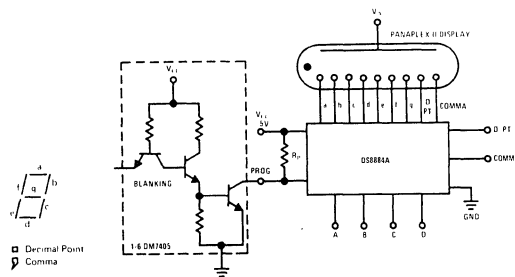
Note 5: In all applications transient segment output current must be limited to 50 mA. This may be accomplished in dc applications by connecting a 2.2k resistor from the anode-supply filter capacitor to the display anode, or by current limiting the anode driver in multiplex applications.

Truth Table

FUNCTION	DPT	COMMA	D	C	B	A	a	b	c	d	e	f	g	DISPLAY
0	1	1	0	0	0	0	0	0	0	0	0	0	0	0
1	1	1	0	0	0	1	0	0	0	1	1	1	1	1
2	1	1	0	0	1	0	0	0	1	0	0	1	0	0
3	1	1	0	0	1	1	0	0	0	0	1	1	0	0
4	1	1	0	1	0	0	0	1	0	0	1	1	0	0
5	1	1	0	1	0	1	0	0	1	0	0	1	0	0
6	1	1	0	1	1	0	0	0	1	0	0	1	0	0
7	1	1	0	1	1	1	0	0	0	0	1	1	1	1
8	1	1	1	0	0	0	0	0	0	0	0	0	0	0
9	1	1	1	0	0	1	0	0	0	0	0	1	0	0
10	1	1	1	1	0	1	0	1	1	0	0	0	1	1
11	1	1	1	1	0	1	1	1	1	0	0	0	1	0
12	1	1	1	1	1	0	0	0	0	0	1	1	0	0
13	1	1	1	1	1	1	0	1	0	1	0	0	0	0
14	1	1	1	1	1	1	0	1	1	1	1	1	1	0
15	1	1	1	1	1	1	1	1	1	1	1	1	1	1
*DPT	0	1	X	X	X	X	X	X	X	X	X	X	X	*
*Comma	0	0	X	X	X	X	X	X	X	X	X	X	X	*

*Decimal point and comma can be displayed with or without any numeral.

Typical Application



Typical Performance Characteristics (see DS7880 data sheet)

DS8885 MOS to High Voltage Cathode Buffer

General Description

The DS8885 interfaces MOS calculator or counter-latch-decoder-driver circuits directly to 7-segment, high-voltage, gas-filled displays. The six inputs A, B, D, E, F, G are decoded to drive the 7-segment of the tube.

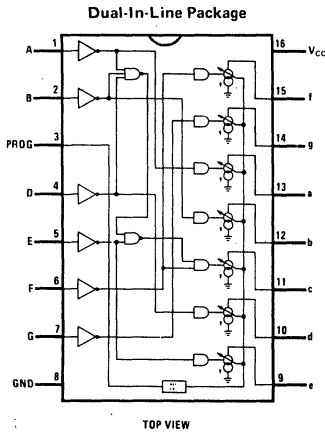
Each output constitutes a switchable, adjustable current source which provides constant current to the tube segment, even with high tube anode supply tolerance or fluctuation. These current sources have a voltage compliance from 3V to at least 80V. Each current source is ratioed to the b-output current as required for even illumination of all segments. Output currents may be varied over the 0.2 to 1.5 mA range for driving various tube types or

multiplex operation. The output current is adjusted by connecting a program resistor (R_P) from V_{CC} to the program input.

Features

- Current source outputs
- Adjustable output currents 0.2 to 1.5 mA
- High output breakdown voltage 80V min.
- Suitable for multiplex operation
- Low fan-in and low power
- Blanking via program input
- Also drives overrange, polarity, decimal point cathodes

Connection Diagram

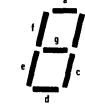


Truth Tables

A	B	D	E	F	G	DISPLAY
1	1	1	1	1	0	0
0	1	0	0	0	0	1
1	1	1	1	0	1	2
1	1	1	0	0	1	3
0	1	0	0	1	1	4
1	0	1	0	1	1	5
1	0	1	1	1	1	6
1	1	0	0	0	0	7
1	1	1	1	1	1	8
1	1	1	0	1	1	9
0	0	1	1	1	1	0
1	1	0	0	1	1	1
1	1	0	1	1	1	2
0	1	0	1	1	1	3
0	1	1	1	1	0	4
0	0	0	0	0	1	5
0	0	0	0	0	0	6

INPUT*	OUTPUT*
0	1 (OFF)
1	0 (ON)

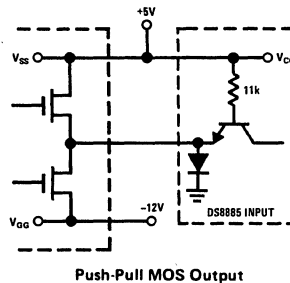
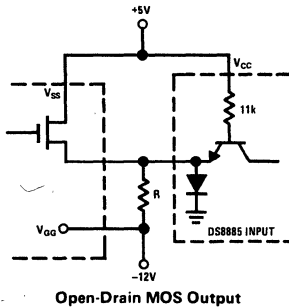
*Positive Logic



C - (A B D · E) F

Order Number DS8885J or DS8885N
See NS Package J16A or N16A

Typical Applications



Absolute Maximum Ratings (Note 1)

V_{CC}	7V
Input Voltage	6V
Segment Output Voltage	80V
Power Dissipation	600 mW
Transient Segment Output Current (Note 4)	50 mA
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.06 mW/°C above 25°C; derate molded package 11.81 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	4.75	5.25	V
Temperature (T_A)	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V_{IH} Logical "1" Input Voltage	$V_{CC} = \text{Min}$	2.0			V	
V_{IL} Logical "0" Input Voltage	$V_{CC} = \text{Min}$			0.8	V	
I_{IH} Logical "1" Input Current	$V_{CC} = \text{Max}$	$V_{IN} = 2.4V$	2	15	μA	
		$V_{IN} = 5.5V$	4	400	μA	
I_{IL} Logical "0" Input Current	$V_{CC} = \text{Max}, V_{IN} = 0.4V$		-300	-600	μA	
I_{CC} Power Supply Current	$V_{CC} = \text{Max}, \text{All Inputs} = 0V, R_P = 2.2k$		22	31	mA	
V_I Input Diode Clamp Voltage	$V_{CC} = 5V, I_{IN} = -12 \text{ mA}, T_A = 25^\circ C$		-0.9	-1.5	V	
SEGMENT OUTPUTS						
I_O "ON" Current Ratio	All Outputs = 50V, $I_{OUT} b = \text{Ref.}$	Outputs a, f, and g	0.84	0.93	1.02	
		Output c	1.12	1.25	1.38	
		Output d	0.90	1.00	1.10	
		Output e	0.99	1.10	1.21	
$I_{b ON}$ Output b "ON" Current	$V_{CC} = 5V, V_{OUT} b = 50V,$ $T_A = 25^\circ C$	$R_P = 18.1k$	0.15	0.20	0.25	mA
		$R_P = 7.03k$	0.45	0.50	0.55	mA
		$R_P = 3.40k$	0.90	1.00	1.10	mA
		$R_P = 2.20k$	1.35	1.50	1.65	mA
V_{SAT} Output Saturation Voltage	$V_{CC} = \text{Min}, I_{OUT} b = 2 \text{ mA}, R_P = 1k \pm 5\%, (\text{Note } 5)$		0.8	2.5	V	
I_{CEX} Output Leakage Current	$V_{OUT} = 75V, V_{IN} = 0.8V, R_P = 1k$		0.003	3	μA	
V_{BR} Output Breakdown Voltage	$I_{OUT} = 250\mu A, V_{IN} = 0.8V$	80	110		V	
t_{pd} Propagation Delay of Input to Segment Output	$V_{CC} = 5V, T_A = 25^\circ C$		0.4	10	μs	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS8885. All typical values are for $T_A = 25^\circ C$ and $V_{CC} = 5V$.

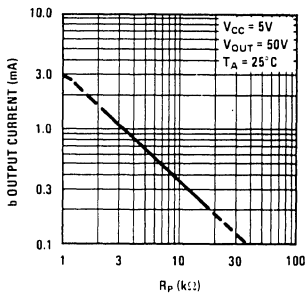
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: In all applications transient segment output current must be limited to 50 mA. This may be accomplished in dc applications by connecting a 2.2k resistor from the anode-supply filter capacitor to the display anode, or by current limiting the anode drive in multiplex applications.

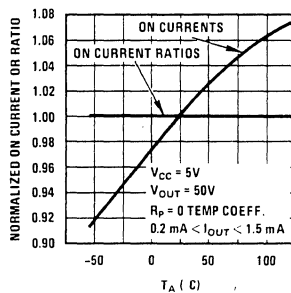
Note 5: For saturation mode the segment output currents are externally limited and ratioed.

Typical Performance Characteristics

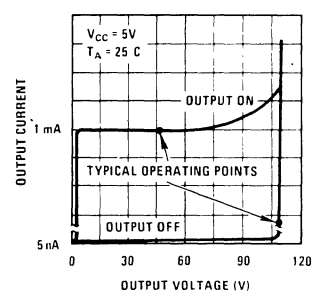
Output Current Programming



On Currents vs Temperature



Output Characteristic





Display Controllers/Drivers

DS8887 8-Digit High Voltage Anode Driver (Active-High Inputs)

DS7889/DS8889 8-Segment High Voltage Cathode Driver (Active-High Inputs)

DS7897A/DS8897A 8-Digit High Voltage Anode Driver (Active-Low Inputs)

General Description

The DS8887 and DS7897A/DS8897A are designed to drive the individual anodes of a 7-segment (cathodes) high-voltage gas discharge panel in a time multiplexed fashion.

When driven with appropriate input signals, the driver will switch voltage and impedance levels at the anode. This will allow or prevent ionization of gas around selected cathode in order to form a numeric display. This main application is to interface with MOS outputs (fully-decoded) and the anodes of a gas-discharge panel, since the devices can source up to 16 mA at a low impedance and can tolerate more than 55V in the "OFF" state.

DS7889/DS8889 is capable of driving 8 segments of a high-voltage display tube with a constant

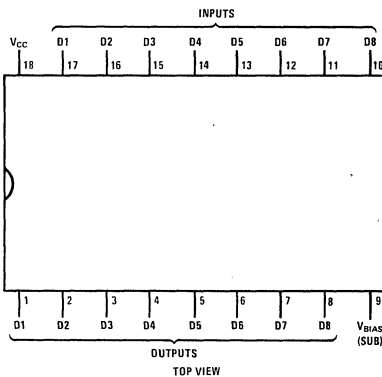
output sink current, which can be adjusted by external program resistor, R_p . The program current is half that of output "ON" current. In the "OFF" state the outputs can tolerate more than 80V. The ratio of "ON" output currents is within $\pm 10\%$. Inputs have negative clamp diodes. Active high input logic. The main application of the device is to interface MOS circuits to high-voltage displays. Unused outputs should have corresponding inputs connected to V_{EE} .

Features

- Versatile circuits for a wide range of display applications
- High breakdown voltages
- Low power dissipation

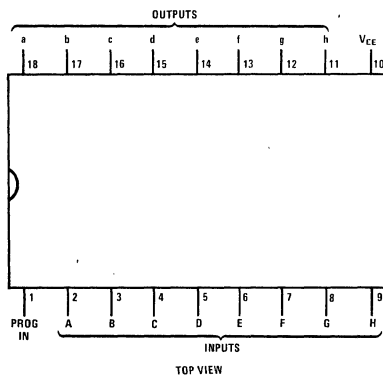
Connection Diagrams (dual-in-line packages)

DS8887, DS7897/DS8897



Order Number DS7897AJ, DS8887J,
DS8897AJ or DS8897AN
See NS Package J18A or N18A

DS7889/DS8889



Order Number DS7889J, DS8889J
or DS8889N
See NS Package J18A or N18A



Absolute Maximum Ratings (Note 1)

Supply Voltage ($V_{CC} - V_{BIAS}$) (Note 2)		
DS8887, DS7897A, DS8897A	-60V	
Input Voltage		
DS8887, DS7897A/DS8897A	-20V	
DS7889/DS8889 (Note 3)	35V	
Output Voltage		
DS8887, DS7897A/DS8897A	-65V	
DS7889/DS8889	85V	
Storage Temperature Range	-65°C to +150°C	
DS7889/DS8889 Maximum Power Dissipation* at 25°C		
Cavity Package	1436 mW	
Molded Package	1563 mW	
DS8887, DS7897A/DS8897A Maximum Power Dissipation† at 25°C		
Cavity Package	1496 mW	
Molded Package	1714 mW	
Lead Temperature (Soldering, 10 seconds)	300°C	

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage ($V_{CC} - V_{BIAS}$)			
DS8887, DS7897A/DS8897A	-40	-60	V
Temperature (T_A)			
DS7889, DS7897A	-55	+125	°C
DS8887, DS8889, DS8897A	0	+70	°C

*Derate cavity package 11.49 mW/°C above 25°C; derate molded package 12.5 mW/°C above 25°C.

†Derate cavity package 11.97 mW/°C above 25°C; derate molded package 13.71 mW/°C above 25°C.

Electrical Characteristics (Notes 2, 3 and 4)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS		
DS8887, DS8897A, DS7897A								
V_{IH}	Logical "1" Input Voltage	$V_{OUT} = -1.4V, I_{OUT} = -16\text{ mA}, \text{DS8887}$	-2.0			V		
V_{IL}	Logical "0" Input Voltage	$V_{OUT} = -60V, I_{OUT} = -100\mu\text{A}, \text{DS8887}$			-5.5	V		
I_{IH}	Logical "1" Input Current	$V_{OUT} = -1.4V, I_{OUT} = -16\text{ mA}, \text{DS8897A, DS7897A}$	-300			μA		
I_{IL}	Logical "0" Input Current	$V_{OUT} = -60V, I_{OUT} = -100\mu\text{A}, \text{DS8897A, DS7897A}$			-10	μA		
I_I	Input Current	DS8887	$V_{IN} = -1.0V$	335	550	μA		
			$V_{IN} = -6.0V$	-0.2	-25	μA		
		DS7897A, DS8897A, $V_{IN} = -12V$	$V_{IN} = -12V$	-0.10	-0.65	mA		
				-0.45	-1.5	mA		
$V_{OUT\ OFF}$	Output "OFF" Voltage	$I_{OUT} = -100\mu\text{A}, I_{IN} = 0\mu\text{A}$	-60	-77		V		
$I_{OUT\ OFF}$	Output "OFF" Current	$V_{OUT} = -55V, I_{IN} = 0\mu\text{A}$		-0.03	-5.0	μA		
$V_{OUT\ ON}$	Output "ON" Voltage	$I_{OUT} = -16\text{ mA}$	$V_{IN} = -2.0V, \text{DS8887}$	-1.0	-1.4	V		
				$I_{IN} = -300\mu\text{A}, \text{DS8897A, DS7897A}$		-1.4	V	
I_{BIAS}	V_{BIAS} Current	$I_{OUT} = -16\text{ mA}, V_{BIAS} = -60V$	$V_{IN} = -1.0V, \text{DS8887, (Note 5)}$ $I_{IN} = -300\mu\text{A}, \text{DS8897A, DS7897A}$ (One Driver Only)	-2.2	-4.0	mA		
					-1.0	mA		
DS7889/DS8889								
I_I	Input Current	$V_{IN} = 6.0V$	150	250	350	μA		
I_{IL}	Logical "0" Input Current	$I_{OUT} = 5.0\mu\text{A}, V_{OUT} = 75V$			7.0	μA		
I_{IH}	Logical "1" Input Current	$I_{OUT} = 1.4\text{ mA}, I_{IP} = 850\mu\text{A}, V_{OUT} = 50V$	80			μA		
V_I	Input Clamp Voltage	$I_{IN} = -1.0\text{ mA}, T_A = 25^\circ\text{C}$		-0.68	-0.85	V		
V_{OH}	Output Breakdown Voltage	$I_{OUT} = 100\mu\text{A}, I_{IN} = 0\mu\text{A}$	80			V		
I_{CEX}	Output Leakage Current	$V_{OUT} = 75V, -0.1\text{ mA} \leq I_{IN} \leq 7.0\mu\text{A}$		0.02	5.0	μA		
I_{PROG}	Prog. Input Voltage	$I_{IP} = 150\mu\text{A}$	1.8	2.3		V		
		$I_{IP} = 850\mu\text{A}$		4.0	4.5	V		
I_{OL}	Logical "0" Output Current	$V_{OUT} = 50V,$ $80\mu\text{A} \leq I_{IN} \leq I_{IP}$	$I_{IP} = 150\mu\text{A}$	DS7889	210	300	390	μA
				DS8889	240	300	360	μA
			$I_{IP} = 400\mu\text{A}$	DS7889	660	800	940	μA
				DS8889	680	800	920	μA
			$I_{IP} = 850\mu\text{A}$	DS7889	1.45	1.7	1.95	mA
				DS8889	1.53	1.7	1.87	mA
ΔI_O	Output Current Ratio	$I_{OUT\ b\ Ref} = 1.7\text{ mA}, V_{OUT} = 50V$	0.9	1.0	1.1			

Switching Characteristics $T_A = 25^\circ\text{C}$ unless otherwise specified.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
DS8887					
t_{ON}	Propagation Delay from Input to Output "ON"	(See ac Test Circuit and Switching Time Waveforms)		5.0	μs
t_{RISE}	Propagation Delay from Input to Output "ON"	(See ac Test Circuit and Switching Time Waveforms)		1.0	μs
DS7889/DS8889					
t_{pd0}	Propagation Delay to a Logical "0" from Input to Output	$R_P = 6.0\text{k}$ to 6.0V , $R_{OUT} = 1.0\text{k}$ to 6.0V		37	ns
t_{pd1}	Propagation Delay to a Logical "1" from Input to Output	Input Ramp Rate $\leq 15\text{ ns}$, Freq = 1.0 MHz dc = 50% , Amplitude = 6.0V		92	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

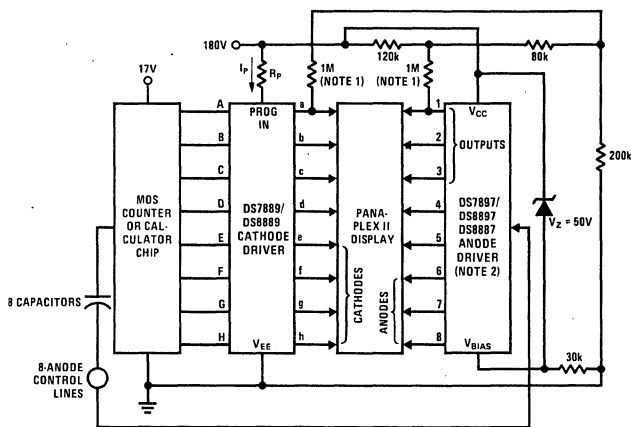
Note 2: All voltage shown for DS8887, DS7897A/DS8897A W.R.T. $V_{CC} = 0\text{V}$. All currents into device pins shown as positive, out of device pins as negative. All values shown as max or min on absolute basis.

Note 3: All voltages for DS7889/DS8889 with respect to $V_{EE} = 0\text{V}$.

Note 4: Unless otherwise specified min/max limits apply across the -55°C to $+125^\circ\text{C}$ temperature range for the DS7889 and DS7897A, and across the 0°C to $+70^\circ\text{C}$ range for the DS8887, DS8889 and DS8897A. All typicals are given for $T_A = 25^\circ\text{C}$.

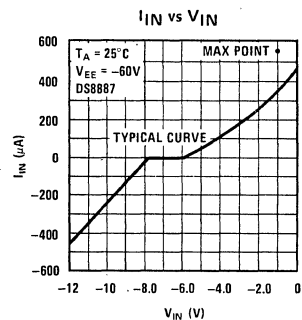
Note 5: Supply currents specified for any one input = -1.0V . All other inputs = -5.5V and selected output having 16 mA load.

Typical Application

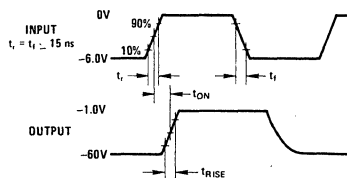
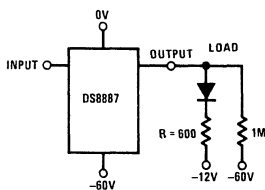


Note 1: All outputs of both cathode and anode driver have loads as shown for output a and digit 1.
Note 2: Use DS8887 for active-high inputs and DS8897 for active-low inputs.

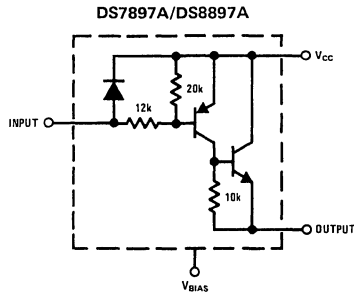
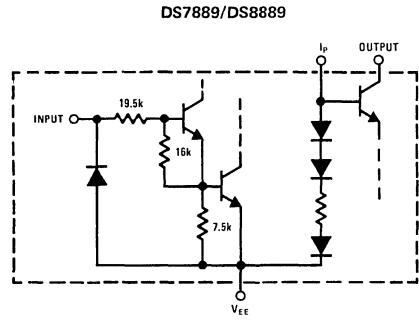
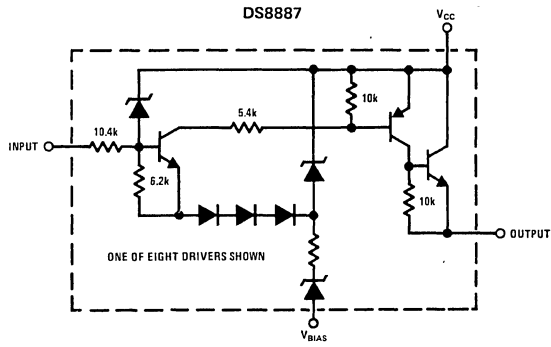
Typical Performance Characteristics



AC Test Circuit and Switching Time Waveforms



Logic Diagrams



DS8887, DS78/8889, DS78/8897A

5

DS8891A High Voltage Anode Drivers (Active-Low Inputs)

General Description

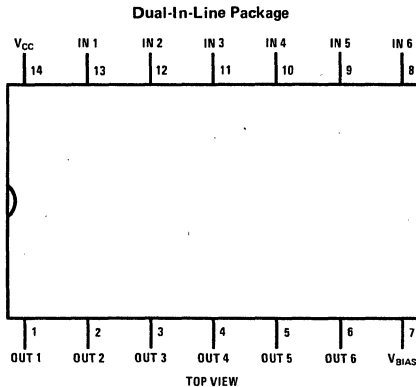
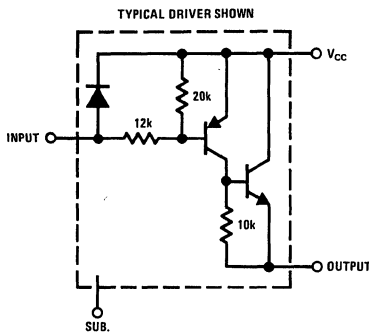
The DS8891A is a 6 digit anode driver intended for use with seven segment, common anode, high voltage, gas discharge display panels operating in a multiplexed mode. The driver switches voltage and impedance levels at the display's anode allowing or preventing ionization of gas around selected cathodes, forming a numeric display. The device acts as a buffer between MOS outputs (fully decoded) and the anodes of a gas-discharge panel,

and it can source up to 16 mA at a low impedance and can withstand more than 55V in the off state.

Features

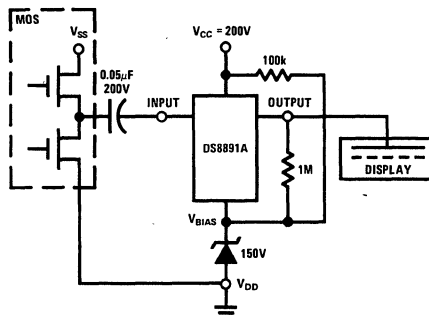
- High breakdown voltage
- Low power dissipation
- Easy interface to clock and calculator circuits

Schematic and Connection Diagrams



Typical Application

Order Number DS8891AJ
or DS8891AN
See NS Package J14A or N14A



Absolute Maximum Ratings (Note 1)

Supply Voltage ($V_{CC} - V_{BIAS}$)	-60V
Input Voltage	-20V
Output Voltage	-65V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation * at 25°C	
Cavity Package	1433 mW
Molded Package	1398 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.55 mW/°C above 25°C; derate molded package 11.18 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, $V_{CC} - V_{BIAS}$	-45	-55	V
Temperature, T_A	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
I_{IN} Input Current	$V_{BIAS} = \text{Min}, V_{IN} = -12V$	-0.6		-1.5	mA
I_{IH} Logical "1" Input Current	$V_{BIAS} = \text{Min}, V_{OL} = -2.0V$	-300			μA
I_{IL} Logical "0" Input Current	$V_{BIAS} = \text{Min}, V_{OUT} = -60V, I_{OUT} = -100\mu A$			-10	μA
I_{OH} Logical "1" Output Current	$V_{BIAS} = \text{Max}, I_{IN} = 0\mu A, V_{OH} = -55V$			-5	μA
V_{OL} Logical "0" Output Voltage	$I_{OL} = -16 \text{ mA}, I_{IH} = -300\mu A$			-2.0	V
V_{BD} Output Breakdown Voltage	$V_{BIAS} = \text{Max}, I_{IN} = 0\mu A, I_{OUT} = -100\mu A$	-60			V
I_{BIAS} Supply Current (Substrate)	$V_{BIAS} = \text{Max}, I_{IH} = -300\mu A, I_{OL} = -16 \text{ mA},$ (One Driver Only)			-1.0	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS8891A.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to $V_{CC} = 0V$, unless otherwise noted. All values shown as max or min on absolute value basis.

DS8973, DS8975 9-Digit LED Drivers

General Description

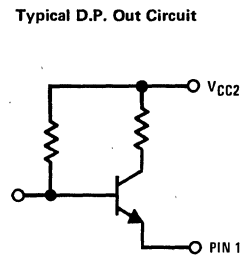
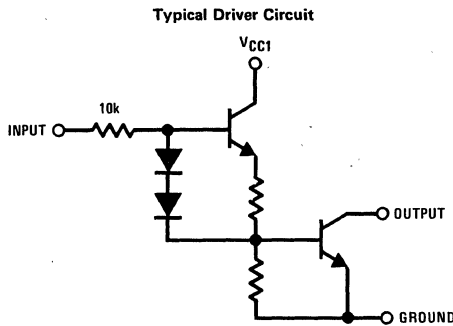
The DS8973 is a 9-digit driver designed to operate from 3-cell battery supplies. Each driver will sink 100 mA to less than 0.7V when driven by only 0.1 mA. Each input is blocked by diodes so that the input can be driven below ground with virtually no current drain. This is especially important in calculator systems employing a dc-to-dc converter on the negative side of the battery. If the converter were on the positive side of the battery, the converter would have to handle all of the display current, as well as the MOS calculator chip current. But if it is on the negative side, it only

has to handle the MOS current. The DS8973 is designed for the more efficient operating mode. The DS8975 is identical to the DS8973 but does not specify the low battery indicator.

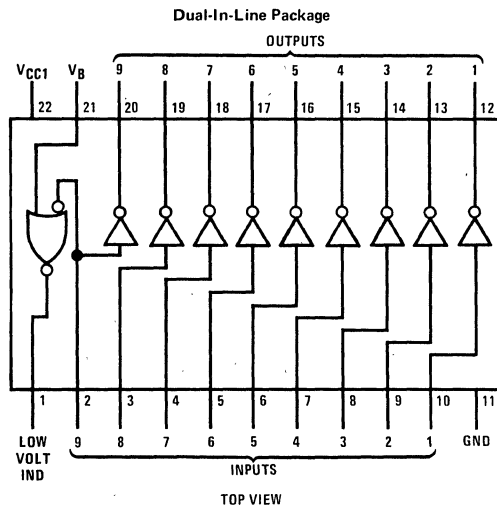
Features

- Nine complete digit drivers
- Built-in low battery indicator
- High current outputs—100 mA
- Straight through pin out for easy board layout

Equivalent Circuit Diagrams



Connection Diagrams



Order Number DS8973N or DS8975N
See NS Package N22A

Absolute Maximum Ratings (Note 1)

Supply Voltage	10V
Input Voltage	10V
Output Voltage	10V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1673 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 13.39 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _B)	3.0	5.5	V
Supply Voltage (V _{CC1})	3.0	9.5	V
Temperature (T _A)	0	+70	°C

Electrical Characteristics

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{IH} Logical "1" Input Voltage	V _{CC} = Max	3.9			V
I _{IH} Logical "1" Input Current	V _{CC} = Max, V _{IH} = 3.9V	0.1		0.3	mA
V _{IL} Logical "0" Input Voltage	V _{CC} = Max			0.5	V
I _{IL} Logical "0" Input Current	V _{CC} = Max, V _{IL} = 0.5V			40	μA
V _{BH} High Battery Threshold	V _{OT} (Pin 1) = 1V, I _{OT} ≤ -50μA, T _A = 25°C, V _{IH} (Pin 2) = 3.9V	DS8973	3.6		V
V _{BL} Low Battery Threshold	V _{OT} (Pin 1) = 2.1V, I _{OT} ≥ -6 mA, T _A = 25°C, V _{IH} (Pin 2) = 3.9V	DS8973		3.2	V
I _{CEX} Logical "1" Output Current	V _{CC} = Min, V _{OH} = 9.5V, V _{IL} = 0.5V			50	μA
V _{OL} Logical "0" Output Voltage	V _{CC} = Min, I _{OL} = 100 mA, V _{IH} = 3.9V			0.7	V
I _{CC1} Supply Current	V _{CC} = Max, One Input "ON"			6	mA
I _B Pin 21 (High Battery Supply)	V _{CC} = Max, V _B = Max			1.2	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to +70°C range. All typicals are given for T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Typical Applications

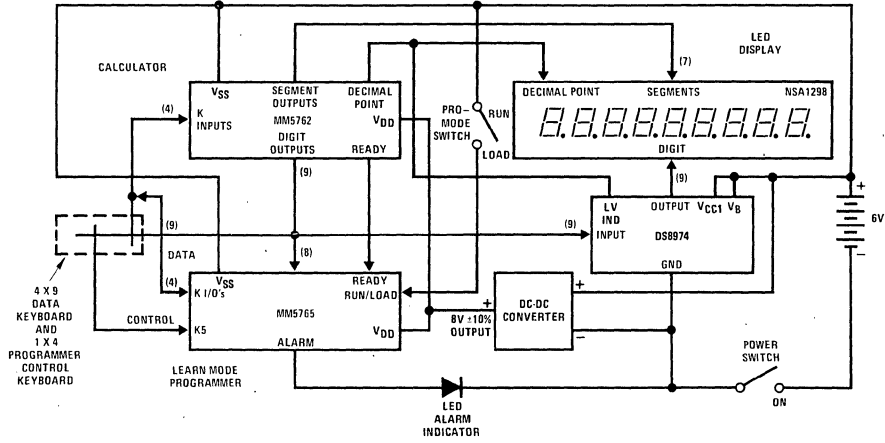


FIGURE 1. 6V Programmable Statistical Calculator

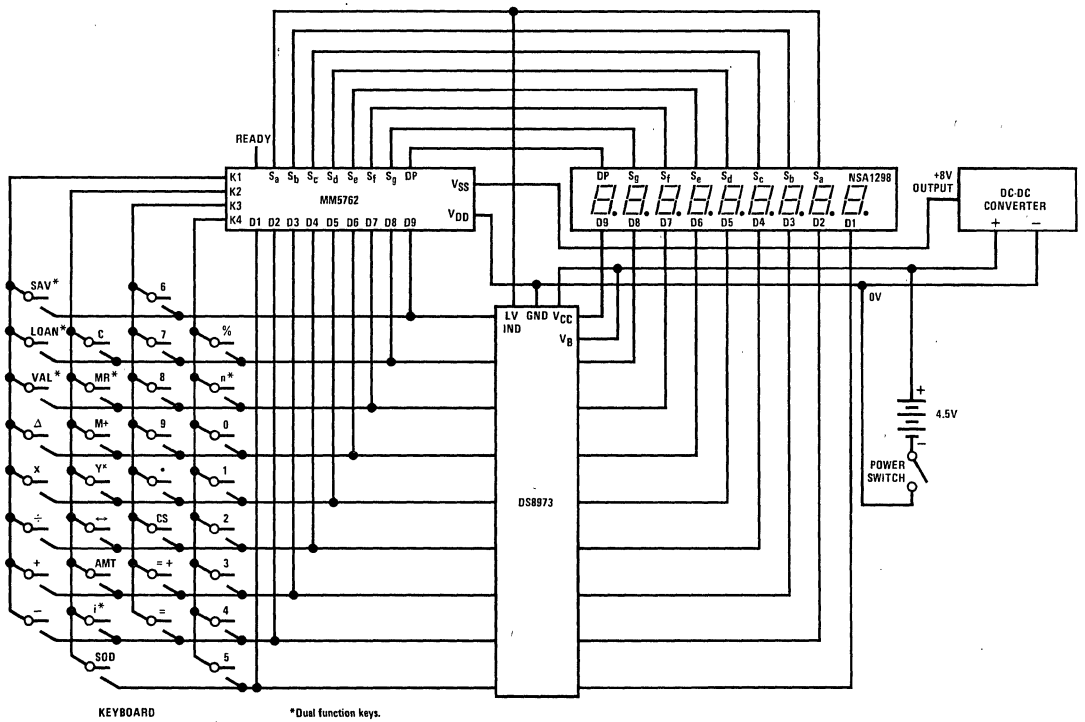


FIGURE 2. Complete Calculator Schematic For 3-Cell System

Driving 7-Segment Gas Discharge Display Tubes with National Semiconductor Circuits



INTRODUCTION

Circuitry for driving high voltage cold cathode gas discharge 7-segment displays, such as Sperry Information Displays* and Burroughs Panaplex II, is greatly simplified by a complete line of monolithic integrated circuits from National Semiconductor. These products also make possible reduced cost of system implementation. They are: DS8880 high voltage cathode decoder/driver; DS8884A high voltage cathode decoder/driver; DS8885 MOS to high voltage cathode buffer; DS8889 low power cathode driver; DS8887 8-digit anode driver; DS8980, DS8981 latch/decoder/cathode drivers.

In addition to satisfying all the displays' parameter requirements, including high output breakdown voltage, these circuits have capability of programming segment current, and providing constant current sinking for the display segments. This feature alleviates the problem of achieving uniformity of brightness with unregulated display anode voltage. The National circuits can drive the displays directly.

Sperry Information Displays* and Burroughs Panaplex II are used principally in calculators and digital instruments. These 7-segment, multi-digit displays form characters by passing controlled currents through the appropriate anode/segment combinations. The cathode in any digit will glow when a voltage greater than the ionization voltage is applied between it (the cathode) and the anode for that digit. In the multiplexed mode of operation, a digit position is selected by driving the anode for that digit with a positive voltage pulse. At the same time, the selected cathode segments are driven with a negative current pulse. This causes the potential between the anode and the selected cathodes to exceed the ionization level, causing a visible glow discharge.

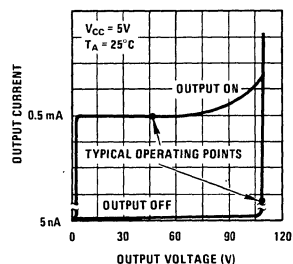
Generally, these displays exhibit the following characteristics: low "on" current per segment—from $200\mu\text{A}$ (in DC mode) to 1.2 mA (in multiplex mode); high tube anode supply voltage—180V to 200V; and moderate ionization voltage—170V. Once the element fires, operating voltage drops to approximately 150V and light output becomes a direct function of current, which is controlled by current limiting or current regulating cathode circuits. Current regulation therefore is most desirable since brightness will then be constant for large anode voltage changes. Tube anode to cathode "off" voltage is approximately 100V; and maximum "off" cathode leakage is $3\mu\text{A}$ to $5\mu\text{A}$.

*Now called Beckman Displays

Correspondingly, specifications for the cathode driver must be complimentary, approximately as follows: A high "off" output breakdown voltage 80V minimum; typical "on" output voltage of 50V; maximum "on" output current of 1.5 mA per segment; and maximum "off" leakage current of $3\mu\text{A}$ to $5\mu\text{A}$.

To allow operation without anode voltage regulation, the cathode driver must be able to sink a constant current in each output, with the output

(a) Cathode Driver Output Characteristic



(b) On Currents vs Temperature

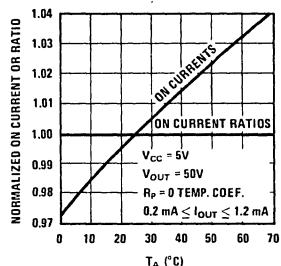


FIGURE 1.

"on" voltage ranging from 5V to 50V (see Figure 1). The following is a brief description of the circuits now offered by National:

DS8880 High Voltage Cathode Decoder/Driver

The DS8880 offers 7-segment outputs with high output breakdown voltage of 80V minimum; constant current-sink outputs; and programmable output current from 0.2 mA to 1.5 mA.

Application

The circuit has a built-in BCD decoder and can interface directly to Sperry and Panaplex II displays, minimizing external components (Figure 2). The inputs can be driven by TTL or MOS outputs directly. It is optimized for use in systems with 5V supplies.

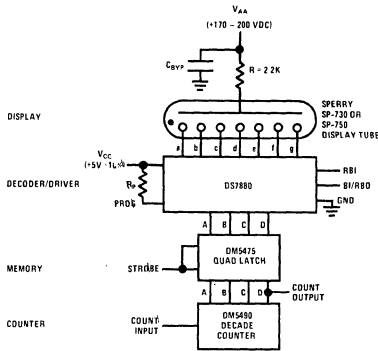


FIGURE 2. DC Operation From TTL

The DS8880 decoder/driver provides for unconditional as well as leading and trailing zero blanking. It utilizes negative input voltage clamp diodes. Typically, output current varies only 1% for output voltage changes of 3V to 50V. Operating power supply voltage is 5V. The device can be used for multiplexed or DC operation.

Available in 16-pin cavity DIP packages, the DS7880 is guaranteed over the full military operating temperature range of -55°C to $+125^{\circ}\text{C}$; the DS8880 in molded DIP over the industrial range of 0°C to $+70^{\circ}\text{C}$.

DS8980, DS8981

The DS8980, DS8981 offer 7-segment and decimal point outputs with high output breakdown voltage of 80V minimum, constant current, programmable from 0.1 mA to 4.0 mA and independent of the V_{CC} voltage, latched BCD inputs and decimal point input.

Application

The circuits have similar applications as DS8880. The devices will operate with a power supply

range of from 4.75V to 15.0V. The input fall-through latches are enabled by a high logic level at the enable input for the DS8980, and by a low logic level for the DS8981.

Available in 18-pin molded dual-in-line packages, and guaranteed over the commercial range of 0°C to $+70^{\circ}\text{C}$.

DS8884A High Voltage Cathode Decoder/Driver

The DS8884A offers 9-segment outputs with high output breakdown voltage of 80V minimum; constant current-sink outputs, programmable from 0.2 mA to 1.2 mA. It also offers input negative and positive voltage clamp diodes for DC restoring, and low input load current of -0.25 mA maximum.

Application

DS8884A decodes four lines of BCD input and drives 7-segment digits of gas-filled displays. There are two separate inputs and two additional outputs for direct control of decimal point and comma cathodes. The inputs can be DC coupled to TTL (Figure 3) or MOS outputs (Figure 4), or AC-coupled to TTL or MOS outputs (Figure 5) using only a capacitor. This means the device is useful in applications where level shifting is required. It can be used in multiplexed operation, and is available in an 18-pin molded DIP package.

Other advantages of the DS8884A are: typical output current variation of 1% for output voltage changes of 3V to 50V; and operating power supply

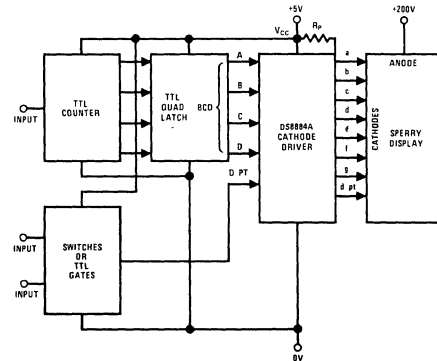


FIGURE 3. Interfacing Directly With TTL Output

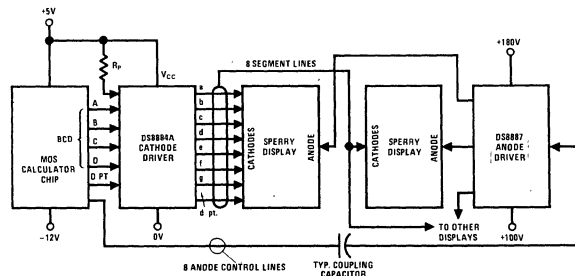
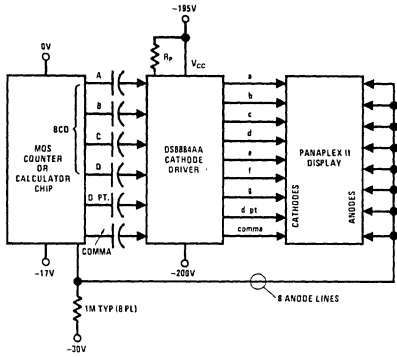


FIGURE 4. BCD Data Interfacing Directly With MOS Output



NOTE: Capacitive coupling between the logic and the segment drivers may be used only when the segment drivers are turned "OFF" during digit-to-digit transitions.

FIGURE 5. Cathode BCD Data AC Coupled From MOS Output

voltage of 5V. Inputs have pull-up resistors to increase noise immunity in AC coupled applications.

The DS8884A is guaranteed over the 0°C to +70°C operating temperature range.

DS8885 MOS to High Voltage Cathode Buffer

The DS8885 features seven constant current-sink outputs; programmable output current of 0.2 mA to 1.5 mA; high output breakdown voltage of 80V minimum; and capability for blanking through program current input. It operates from a +5V supply.

Application

DS8885 is best suited for interfacing 7-segment fully decoded MOS chips to digit displays. It is also useful for driving polarity, overrange, and decimal point segments.

DS8885 has 6 inputs and 7 outputs. Output c is decoded internally; the other 6 outputs are directly controlled by the 6 corresponding inputs. A typical application of this device is interfacing between an MOS calculator chip with 7-segment decoded outputs (open-drain or push-pull) and Sperry/Panaplex II displays (Figure 6).

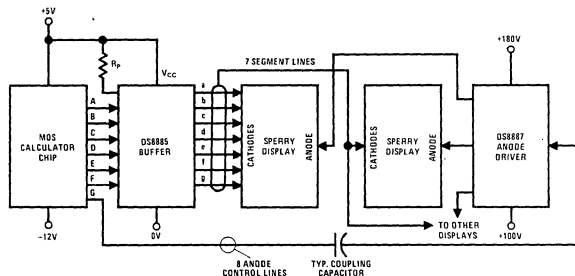
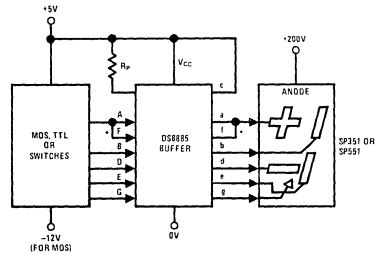


FIGURE 6. Fully Decoded MOS Cathode Outputs

When the DS8885 is used to drive minus and plus (polarity) cathodes, overrange, and decimal points, output c should be tied to V_{CC} so it does not saturate (Figure 7). This leaves 6 inputs and 6 outputs related one-to-one. The inputs can be driven directly from TTL or MOS outputs.



*Output may be paralleled for cathodes requiring more current, providing the corresponding inputs are also paralleled.

FIGURE 7. Polarity, Overrange, Decimal Point Driving

The DS8885 is available in 16-pin molded DIP package, and is guaranteed over the operating temperature range of 0°C to +70°C.

DS8889 Low Power Cathode Driver

The DS8889 requires no power supply since power is derived from program current. It offers extremely low standby power—only 1 mW internally. Features include programmable output currents 0.3 mA to 1.7 mA; 8 constant current-sink outputs; and input negative voltage clamp diodes for DC restoring. Outputs have 80V minimum breakdown voltage.

The device is suitable for multiplexed operation from fully decoded chips and is capable of driving decimal point segments simultaneously with numeric segments.

Application

The DS8889 has 8 inputs and 8 outputs, and interfaces directly between 7-segment decoded MOS outputs and numeric display tubes (Figures 8 and 9). It is optimized for use in systems with a limited number of power supplies.

The program input is characterized in terms of input current, therefore any supply (greater than 5V) can provide proper operation by connecting a single resistor to the program pin from the supply.

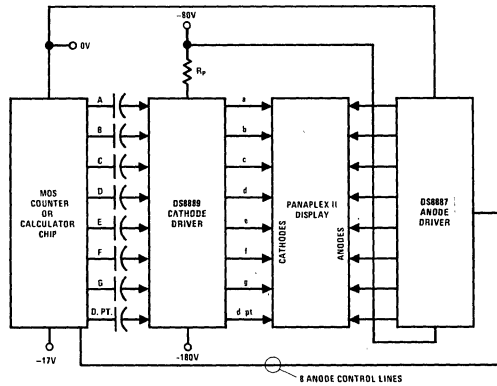
The DS8889, guaranteed for the 0°C to +70°C operating temperature range, is offered in the 18-pin molded DIP.

DS8887 8-Digit Anode Driver

The DS8887 interfaces directly to MOS chips and operates from a -40V to -80V power supply.

The DS8887 can operate virtually any multiplex display system requiring more output performance from the MOS chip than is available (Figures 4, 6, 8 and 9). It has low input current and voltage swing requirements but can drive up to 16 mA, and exhibits -55V minimum output breakdown voltage.

The DS8887 is available in the 18-pin molded DIP package; and is guaranteed over the operating temperature range of 0°C to +70°C.



NOTE: Capacitive coupling between the logic and the segment drivers may be used only when the segment drivers are turned "OFF" during digit-to-digit transitions.

FIGURE 8. Decoded Cathode Data AC Coupled From MOS Output

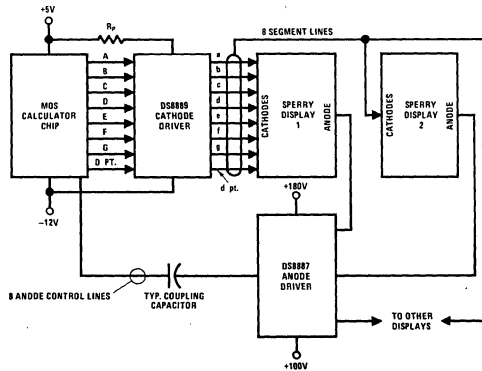


FIGURE 9. Decoded Cathode Data Direct Coupled From MOS Output

Driving 7-Segment LED Displays with National Semiconductor Circuits

National Semiconductor
Application Note 99
Charles Carinalli
May 1974



INTRODUCTION

There are many different information display technologies available today, including liquid crystals, gas-discharge tubes, fluorescent tubes, incandescent lamps, and light emitting diodes (LEDs). Each technology has its own particular drive requirement. This note will focus on 7-segment LED display drive requirements and demonstrate that National Semiconductor has a full line of display drivers that meet the requirements for most any 7-segment LED drive application.

WHY ARE LED DRIVERS NEEDED?

The purpose of 7-segment LED drivers is to act as an interface element between data input and the display. This interface is necessary when either the input data format or circuitry current capabilities do not allow direct connection between input and display. To satisfy these needs, National's 7-segment LED drivers are divided into two basic categories.

1. Internally decoded (BCD to 7-segment)
 - DM5446A/DM7446A
 - DM5447A/DM7447A
 - DM5448/DM7448
 - DM7856/DM8856
 - DM8857
 - DM7858/DM8858

2. Non-decoding, direct drive (MOS to 7-segment)

DM75491	DM8864
DM75492	DM8865
DM8861	DM8866
DM8863	

Thus, National has circuits that will drive 7-segment LEDs from either fully decoded circuits or from non-decoded outputs.

CONFIGURATIONS AND CONSTRUCTION OF 7-SEGMENT LEDs

LEDs are segregated into two groupings with regard to construction, see Figure 1.

Common anode displays are constructed on a common substrate which forms the anode of the diodes, while each of the seven cathodes are bonded out to separate pins. The second type, common cathode, has the cathode fabricated on a common substrate with the anodes bonded out to individual pins. Due to these radically different configurations, drive circuits are usually tailored in their design for one or the other type. Tailoring in this respect means either sinking current (active low) or sourcing current (active high) when referenced to segment drive. In addition, drive requirements are quite variable because of LED light intensity requirements as well as digit size

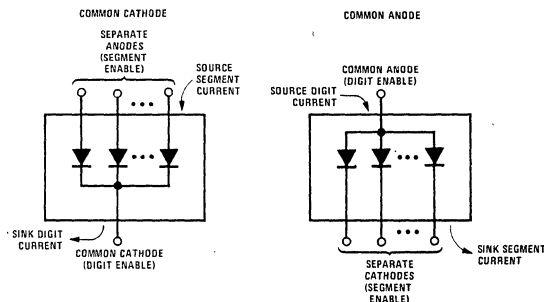


FIGURE 1. 7-Segment LED Construction

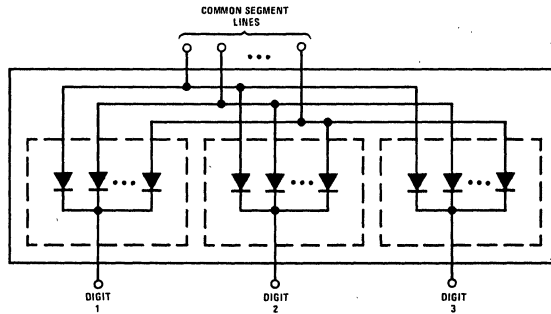


FIGURE 2. Multi-Digit 7-Segment LED

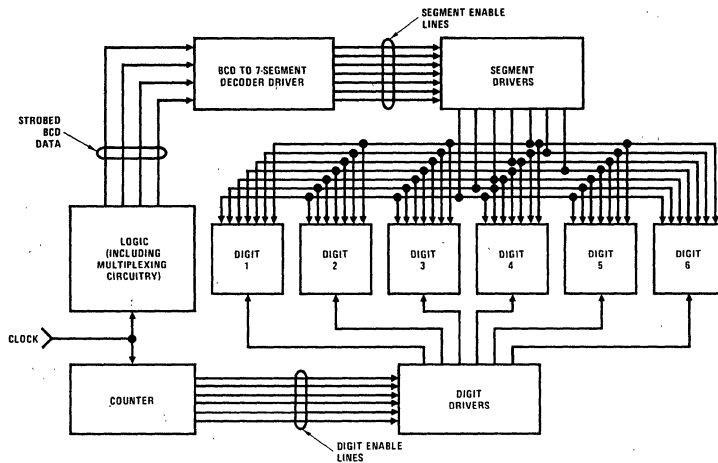


FIGURE 3. A Typical Multiplexing Scheme

and efficiency. Thus the system designer needs a degree of latitude not only with respect to the type of display used but also the drive current available.

7-segment LEDs can be purchased in either single or multi-digit display packages. Single digit displays have individual segment and common pins while multi-digits have paralleled segment pins and separate digit pins equal to the number of digits in the package, see Figure 2.

Multi-digit displays, due to their configuration, must be driven in a multiplex mode of drive, where segment drivers are time shared by all the digits. This is contrasted to the single digit displays which

may be driven in either the multiplex or the non-multiplex (direct drive) mode. The nonmultiplex mode uses separate segment drivers for each digit of the display. Multiplex operation has a decided cost saving advantage over nonmultiplex operation especially when the number of digits being driven is large.

MODES OF 7-SEGMENT LED DRIVE

In the multiplex mode of drive the LED digits in a multi-digit format are driven by a single set of segment drivers while each digit is selected by its own digit driver. Figure 3 shows the circuitry needed to implement a typical six digit multiplexed display.

Each digit is selected individually by enabling its digit driver whose control is determined by a counter or equivalent circuitry operating at some clock frequency. Strobed data, by way of the counter and multiplex circuitry, is then displayed on the selected digit by the single set of segment drivers. If the strobe rate is high enough, from about 250 to 1,000 Hz depending on external conditions, the display will appear flicker free to the human eye. The BCD-to-7-segment decoder converts BCD data to the desired 7-segment output format.

In the multiplex mode each digit has a reduced duty cycle and is operated at somewhat higher than average or typical dc operating current levels. The amount of current will be a function of the number of digits, duty cycle, and the type and efficiency of the display used. Since currents are higher than average so also will be the LED brightness due to the nearly linear brightness versus current curve for most LEDs. The human eye will detect the brightness peaks and through a partially integrating and peak detecting action will perceive a higher display brightness at some average current level in the multiplex mode than the same average current in the nonmultiplex (direct drive) mode. The result is that a multiplexed display will operate at a lower total power than the same display operated in the nonmultiplex mode with the same apparent brightness.

In the nonmultiplex mode of 7-segment LED drive each digit has its own set of segment drivers thereby dropping the digit driver select requirement of multiplexed operation. In this case, the common digit pin may be tied to the highest potential if common anode or the lowest if common cathode. It is evident that in a nonmultiplexed display the driver package count would be high since each digit requires its own set of segment and possibly decoder drivers. If a large number of digits are used the segment driver package count would equal the number of digits while in the multiplex mode this count is equal to one. Granted, in the multiplex mode additional control circuitry is required. Consideration of the relative cost of this circuitry in comparison to the segment decoder driver circuitry in the nonmultiplex mode results, in general, in the fact that if the number of digits in the display equals or is more than four, total package count and/or cost is less in the multiplex mode of drive.

In most MOS circuits multiplex operation is ideal since the counter, multiplexer, and BCD to 7-segment decoders or equivalent circuitry can usually be incorporated on the same chip along with calculator, clock or other function. In this case the only external interface components required would be the digit and segment drivers since MOS circuits are generally unable to sink or source the higher current required for most multiplex operations.

In summary, LED driver requirements for multiplex or nonmultiplex drive operation require either segment, digit or BCD to 7-segment drivers. Analysis of the particular system needs with regard to the number of digits and relative circuit costs should be the determining factor for multiplex or nonmultiplex operation. Circuit requirements for multiplex operation will in general require relatively high current capabilities.

NATIONAL'S 7-SEGMENT LED DRIVERS

Table I lists the 7-segment LED drivers available from National. Each circuit's application is divided into groupings with respect to common anode or cathode, digit or segment, multiplex or nonmultiplex areas. Additionally, current capabilities are also specified for each product.

From the table it is evident that some of the circuits may be used in dual roles — both multiplex or nonmultiplex; common cathode or anode. In general, what will determine whether one driver's application is multiplex or nonmultiplex is that driver's current capability. The direction of current flow through the driver (source or sink) is the determining factor in dual application with regard to common anode or cathode.

Table II lists the operating temperature range and package types for the 7-segment LED drivers.

In the following sections each circuit is described in greater detail and typical applications are given.

BCD TO 7-SEGMENT DECODER DRIVERS

DM5446A/DM7446A, DM5447A/DM7447A, DM5448/DM7448

This family of BCD to 7-segment decoder drivers was designed for the most general possible display drive applications including display technologies other than LEDs. The difference between the circuits is in their output stage configurations. These differences will be discussed separately later.

The circuits convert the standard 4-bit BCD input to the popular 7-segment output format. All input BCD codes above 9 are decoded into unique patterns that verify operation. The circuits are TTL-DTL compatible and operate off of a single 5.0V supply.

Added features included in all circuits are a ripple blanking input pin as well as a lamp test pin for display turn on. In addition the blanking input/ripple blanking output pin may be used to modulate display intensity.

TABLE I. National 7-Segment LED Drivers

DEVICE NUMBER	COMMON CATHODE		COMMON ANODE		DIGIT DRIVER	SEGMENT DRIVER	INTERNAL DECODING	CURRENT CAPABILITY AND FEATURES
	Multiplex	Nonmultiplex	Multiplex	Nonmultiplex				
DM5446A/DM7446A DM5447A/DM7447A			X	X		X	X	Up to 40 mA Sink, Open Collector High Breakdown (30/15V) TTL Input Compatibility
DM5448/DM7448		X	X*	X*		X	X	1.3 mA Source, Adjustable Externally, TTL Input Compatibility
DM7856/DM8856		X	X*	X*		X	X	6.0 mA Typical Source, TTL Input Compatibility
DM8857	X	X				X	X	50 mA Typical Source, Externally Adjustable, TTL Input Compatibility
DM7858/DM8858	X	X				X	X	Adjustable Source Current 0 to 50 mA, TTL Input Compatibility
DM75491	X	X	X	X	X	X		50 mA Source/Sink, 4 Drivers per Package, MOS Input Compatibility
DM75492	X		X	X	X	X**		250 mA Sink, 6 Drivers per Package, MOS Input Compatibility
DM8861	X	X	X	X	X	X		50 mA Source/Sink, 5 Drivers per Package, MOS Input Compatibility
DM8863	X		X	X	X	X**		500 mA Sink, 8 Drivers per Package, MOS Input Compatibility
DM8864	X		X	X	X	X**		50 mA Sink, 9 Drivers per Package, MOS Input Compatibility
DM8865	X		X	X	X	X**		50 mA Sink, 8 Drivers per Package, MOS Input Compatibility
DM8866	X		X	X	X	X**		50 mA Sink, 7 Drivers per Package, MOS Input Compatibility

*With the use of an external transistor/segment.

**For common anode LED's.

TABLE II. Operating Temperature Range and Package Type

DEVICE NUMBER	OPERATING TEMPERATURE RANGE		NUMBER OF PINS			PACKAGE TYPE		
	0°C to +70°C	-55°C to +125°C	14	16	18	Plastic Molded DIP (N)	Ceramic DIP (J)	Flat Pack (W)
DM5446A, DM5447A		X		X			X	X
DM7446A, DM7447A	X			X		X	X	X
DM5448		X		X			X	X
DM7448	X			X		X	X	X
DM7856		X		X			X	X
DM8856	X			X		X	X	X
DM8857	X			X			X	
DM7858		X		X			X	X
DM8858	X			X		X	X	X
DM75491	X		X			X	X	X
DM75492	X		X			X	X	X
DM8861	X				X	X		
DM8863	X				X	X		
DM8865	X				X	X		
DM8866	X				X	X		
DM8864	X			22		X		

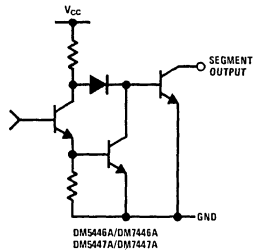


FIGURE 4a. Output Stage

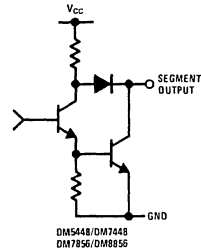
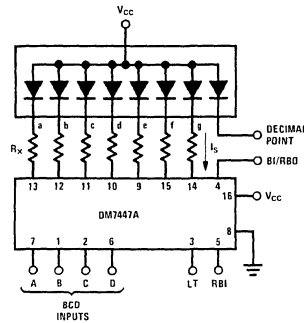


FIGURE 4b. Output Stage



THE FOLLOWING EQUATION MAY BE USED TO DETERMINE THE APPROPRIATE VALUE OF R_x (SEGMENT CURRENT LIMIT RESISTOR) FOR SOME LED CURRENT/SEGMENT I_s (mA).

$$R_x = \frac{V_{CC} - 0.3 - V_{LED} (@ I_s)}{I_s} \quad (1)$$

($I_s \leq 40$ mA)

WHERE $V_{LED} (@ I_s)$ IS THE DIODE (LED) VOLTAGE DROP AT OPERATING CURRENT I_s .

EXAMPLE:

$$I_s = 20 \text{ mA}$$

$$V_{LED} (@ I_s) = 3.4 \text{ V}^*$$

$$V_{CC} = 5.0 \text{ V}$$

$$R_x = 65 \Omega$$

*MAN-1 OR EQUIVALENT

FIGURE 5. Nonmultiplex Application of the DM7447A

DM5446A/DM7446A, DM5447A/DM7447A

These circuits feature active-low, open collector high current outputs (Figure 4a). Each output is capable of sinking up to 40 mA at a maximum internal drop of 0.4V. This high current capability makes these circuits particularly well suited for driving the large MAN-1 or equivalent type displays directly. The circuits are also applicable, with or without the use of external current limit resistors, to driving lower current displays in the multiplex mode of drive.

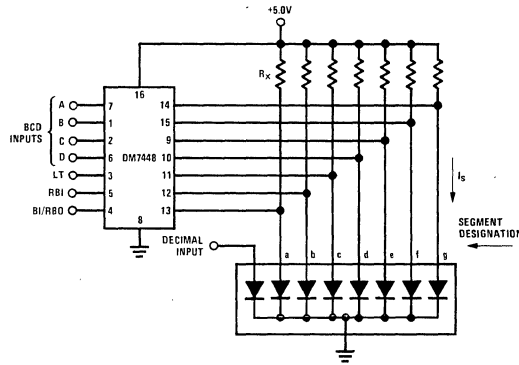
The DM5446A and DM7446A outputs are capable of withstanding 30V at a maximum leakage of 250 μ A over temperature. The DM5447A and DM7447A have a 15V output capability at a maximum leakage over temperature of 250 μ A. This standoff voltage ability makes the circuits applicable for direct drive to indicator lamp type displays. Figure 5 shows a typical application of the circuits with LEDs.

Refer to Table II for the operating temperature range and package types for the DM5446A/DM7446A and DM5447A/DM7447A.

DM5448/DM7448

The DM5448/DM7448 has active high passive pull-up outputs (Figure 4b) with a TTL fanout of 4. The typical output source current is 2.0 mA at an output voltage of 0.85V. Each output is capable of sinking 6.4 mA with a maximum internal drop of 0.4V. Since the output current level is low the circuit can be used to drive low current common cathode displays operating in the nonmultiplex mode.

The major application of the DM5448/DM7448 is to drive logic circuits, operate high-voltage loads such as electroluminescent displays through buffer transistors or SCR switches, or high-current



R_X MAY BE CALCULATED USING THE FOLLOWING EQUATION

$$R_X = \frac{5.0 - V_{LED}}{I_S - 1.6} \text{ k}\Omega = \frac{3.3}{I_S - 1.6} \text{ k}\Omega \quad \left[\begin{array}{l} V_{LED} = 1.7V @ 5.0 \text{ mA} \\ R_X \geq 650\Omega \end{array} \right]$$

WHERE:

R_X = PULL-UP RESISTOR VALUE
 I_S = CURRENT PER SEGMENT IN mA

EXAMPLE:

$I_S = 5.0 \text{ mA}$
 $R_X = 970\Omega$

FIGURE 6. Nonmultiplex Application of the DM7448

loads through buffer transistors. Figure 6 shows the DM7448 in a low current direct drive LED application.

The operating temperature range and package types for the DM5448/DM7448 are given in Table II.

BCD TO 7-SEGMENT LED DRIVERS
DM7856/DM8856, DM8857, DM7858/DM8858

This series of three circuits was designed to provide a wide range of current capabilities in driving common cathode 7-segment LEDs operating in the multiplex or nonmultiplex mode. The circuits, discussed individually below, have output stages with varying source current capability designed for specific as well as general applications.

All circuits accept 4-bit BCD and decode this input to the desired 7-segment output format for direct drive to LEDs. In addition, the circuits feature a lamp test pin for display turn-on check, ripple blanking-input pin and blanking input/ripple blanking output pin which may be used to modulate display intensity.

The three circuits are TTL-DTL compatible and provide full decoding of the 16 possible input combinations. All parts operate off of a single 5.0V supply.

DM7856/DM8856

The DM7856/DM8856 output stages, passive-pullup (active high, Figure 4b), provide a typical

source current of 6.0 mA at an output voltage of 1.7V. This current level was designed for directly driving, without the use of external current limit resistors, the MAN-4 or equivalent type displays in the nonmultiplex mode of operation.

Each output has a fan-out of 4 and is capable of sinking 6.4 mA with a maximum internal drop of 0.4V making the circuit suitable for use with logic circuits. With the use of an external buffer transistor per output the circuit may be used to drive high current common anode LED displays as well as high voltage electroluminescent displays. Figure 7 shows a typical application of the DM8856.

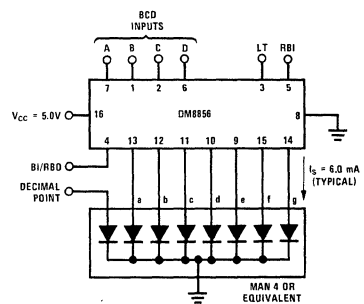


FIGURE 7. Nonmultiplex Application of the DM8856

Operating temperature range and package types for the DM7856/DM8856 are given in Table II.

DM8857

The output stages of the DM8857, active pull-up (active-high, Figure 4c), source a typical current

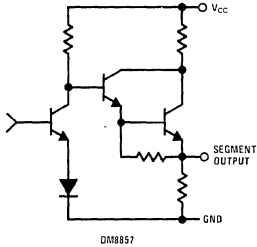


FIGURE 4c. Output Stage

Table II gives the operating temperature range and package type for the DM8857.

DM7858/DM8858

The DM7858/DM8858 output stages are active pull-up (active-high, Figure 4d) like those of the

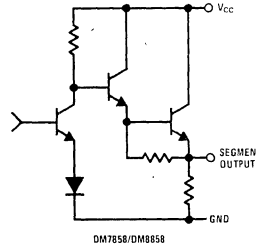


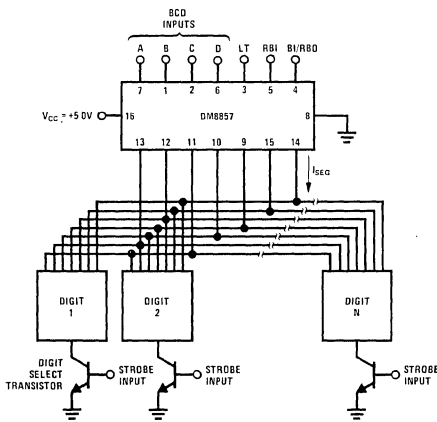
FIGURE 4d. Output Stage

of 50 mA at an output voltage of 2.3V. The circuit was designed to be used with MAN-4 or equivalent type displays operating in the multiplex mode of drive. With this high current capability the circuit can drive up to 16 such digits.

The applications of this circuit obviously are not limited to just the MAN-4 type of display. Common cathode displays with high dc current requirements or lower multiplex current levels may be driven by this circuit with the use of an external current limit resistor per segment. A typical application of the DM8857 is given in Figure 8.

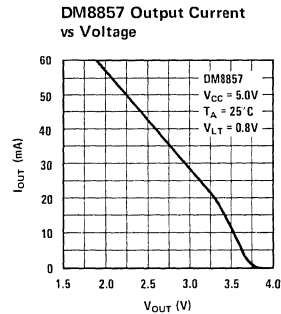
DM8857. The output stages are exactly the same as the DM8857 except that the internal current limit resistor per output has been removed. External current limit resistors must then be used. This allows the circuit to be customized for a particular common cathode multiplex or non-multiplex application. Each output stage, through its own external resistor, can be programmed to some current from 50 mA down to 0 mA. Care must be taken in not shorting the outputs to ground because of the excessive current flow that would result from the Darlington upper stage. See Figure 9 for a typical application of the DM8858.

5



FOR MULTIPLEX OR NONMULTIPLEX APPLICATIONS WHERE AN EXTERNAL CURRENT LIMIT RESISTOR PER SEGMENT IS REQUIRED SEE THE OUTPUT CURRENT VS VOLTAGE CURVE FOR THE DM8857 AND USE THE EQUATION GIVEN IN FIGURE 9 TO CALCULATE THE RESISTOR VALUE.

FIGURE 8. DM8857 Typical Multiplexing Scheme



Maximum output source current per segment for the DM7858/DM8858 is 50 mA. Operating temperature range and package types are given in Table II.

Special care must be taken in the use of the DM7858 ceramic and the DM8858 plastic DIP's with regard to not exceeding the maximum operating junction temperature of the devices. The maximum junction temperature of the DM7858J is 150°C and must be derated based on a thermal resistance of 80°C/Watt, junction to ambient. The maximum junction temperature for the DM8858N is 150°C and must be derated based on a thermal resistance of 140°C/Watt, junction to ambient.

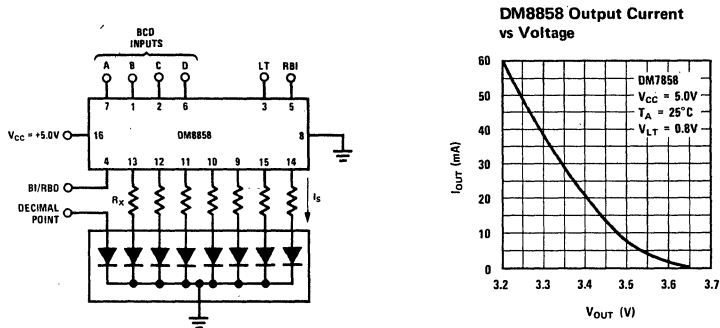
DM75491, DM8861 MOS TO LED SEGMENT DRIVERS

The DM75491 and DM8861 were designed for MOS calculator applications. Both circuits feature

low input current, 3.3 mA maximum at 10V input, making them suitable for direct drive from MOS circuits. The circuits are used to drive the paralleled segments in multi-digit displays. Since both circuits feature accessible collectors and emitters they may be used as either common cathode or anode segment drivers. They feature a source or sink current capability of up to 50 mA with a maximum collector to emitter drop of 1.5V over the operating temperature range. In addition, each output is specified to have a maximum leakage of 100µA at an output voltage of 10V over temperature. Both circuits operate from a single supply that can have a maximum voltage of 10V.

DM75491 FOUR SEGMENT DRIVER

The DM75491 is a four segment driver whose main application is with multi-digit LEDs operating in the multiplex mode of drive. Each package contains four separate segment drivers, each driver



TO FIND THE APPROPRIATE VALUE OF THE SEGMENT CURRENT LIMIT RESISTOR R_x THE FOLLOWING EQUATION SHOULD BE USED.

$$R_x = \frac{V_{OUT} - V_D}{I_S}$$

WHERE:

I_S = SEGMENT CURRENT

V_D = LED DIODE DROP AT CURRENT I_S

V_{OUT} = DM8858 OUTPUT VOLTAGE AT CURRENT I_S (SEE GRAPH)

EXAMPLE:

$I_S = 5.0 \text{ mA}$

$V_D = 1.7\text{V}$ (AT 5.0 mA)

FROM GRAPH ($V_{CC} = 5.0\text{V}$, $T_A = 25^\circ\text{C}$)

$V_{OUT} = 3.53\text{V}$ (AT 5.0 mA)

$$R_x = \frac{3.53\text{V} - 1.7\text{V}}{5.0 \text{ mA}}$$

$R_x = 368\Omega$

THE SAME EQUATION MAY BE USED WHEN EITHER THE DM7858 OR THE DM8858 ARE OPERATING IN THE MULTIPLEX MODE OF DRIVE. IF THE ADDITIONAL VOLTAGE DROP DUE TO THE DIGIT DRIVER IS TAKEN INTO CONSIDERATION THE NEW EQUATION WOULD HAVE THE FOLLOWING FORM:

$$R_x = \frac{V_{OUT} - V_D - V_{DN}}{I_S}$$

V_{DN} = DIGIT DRIVER DROP AT CURRENT I_S

FIGURE 9. DM8858 Applications

with free collector and emitter points, see Figure 4e.

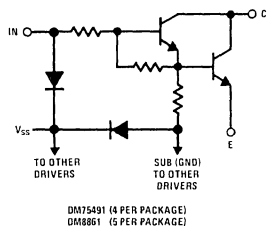


FIGURE 4e. Circuit Schematic

In the multiplex mode of drive, a six digit calculator needs only two DM75491's to drive the segments in the display, see Figure 10. The total of eight segment drivers allows drive to each of the individual seven segments plus logic control for the decimal point. Figure 11 shows the DM75491 used in an 8 digit calculator application.

Table II lists the package type and temperature range of the DM75491.

DM8861 FIVE SEGMENT DRIVER

The DM8861 is a five segment driver which like the DM75491 is used with multi-digit LEDs operating in the multiplex mode of drive. Each package contains five separate drivers, each driver with free collector and emitter points, Figure 4e.

A typical application of the DM8861 is given in Figure 11 where the DM8861 is combined with the DM75491 to provide a total of nine independent sources of LED segment current from an MOS calculator. This allows control of the 7-segments plus decimal point and minus sign. This combination of circuits is not solely applicable to just the 8 digit calculator configuration shown but can be used with a display having as many digits as desired as long as the multiplexed segment current requirement does not exceed 50 mA.

As with the DM75491, the DM8861 is also applicable to use with common anode displays as well as common cathode since each driver has its collector bonded out to a separate pin.

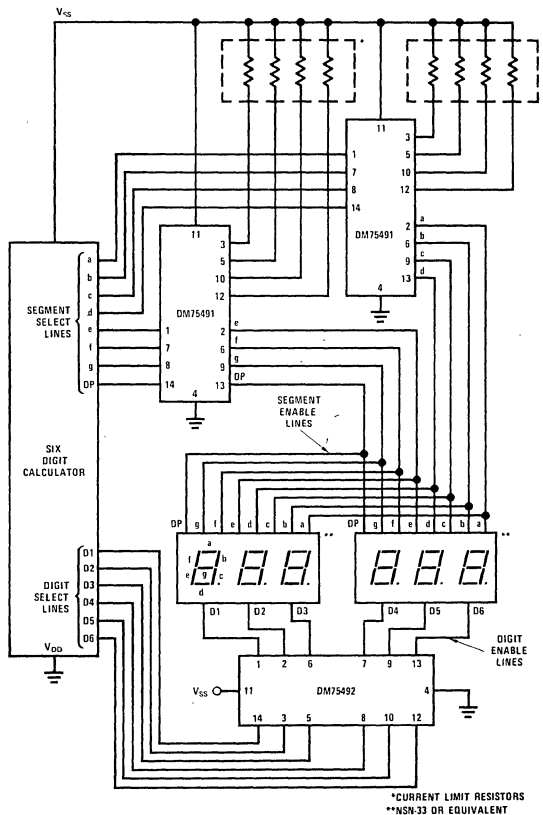


FIGURE 10. 6-Digit Calculator

Refer to Table II for operating temperature range and package type for the DM8861.

DM75492, DM8863 MOS TO LED DIGIT DRIVERS

The DM75492 and DM8863 are digit drivers designed to drive multi-digit common cathode LEDs directly from MOS circuits. Since digit currents are quite high in multiplex operation MOS circuits usually cannot sink the required digit select current, therefore these circuits provide the required current buffering. The two circuits have different current handling capability as well as different numbers of drivers per package, each will be discussed individually later.

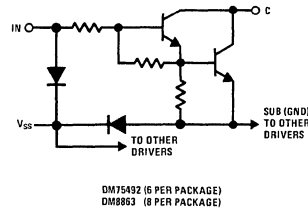
The circuits are totally compatible for use with both the DM75491 and the DM8861. The most common usage of the circuits is in MOS calculator applications where the DM75491 or the DM8861 source the segment current and either the DM75492 or the DM8863 sink the digit current.

DM75492 SIX DIGIT DRIVER

The DM75492 is a six digit LED driver designed to be used with common cathode multi-digit

displays operating in the multiplex mode of drive.

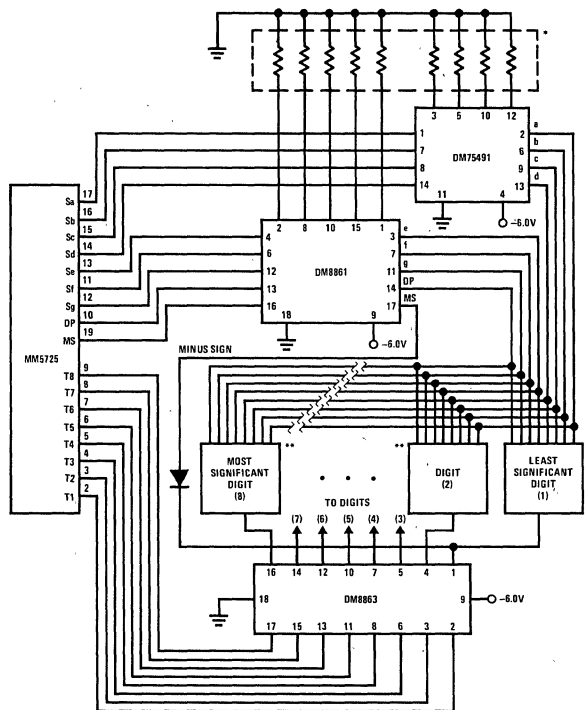
The circuit features six high gain Darlington connected transistors, with collectors open and emitters tied to ground (Figure 4f), capable of



DM75492 (6 PER PACKAGE)
DM8863 (8 PER PACKAGE)

FIGURE 4f. Circuit Schematic

sinking up to 250 mA with a maximum collector to ground drop of 1.5V over the operating temperature range. Low input current of 3.3 mA maximum at 10V makes the drivers suitable for direct connection to MOS circuits. Output leakage is 200µA maximum at 10V over temperature. Maximum V_{CC} is 10V.



*SEGMENT CURRENT LIMIT RESISTORS
**EITHER SINGLE DIGIT, MULTI-DIGIT, NSN 33, OR EQUIVALENT

In Figure 10 the DM75492 is shown along with the DM75491 in a typical six digit calculator application. Since the calculator circuit shown is operated in the multiplex mode of drive only one DM75492 is required, replacing at least six transistors and resistors for the equivalent discrete circuit.

The operating temperature range and package type for the DM75492 is given in Table II.

DM8863 EIGHT DIGIT DRIVER

The DM8863 is an eight digit LED driver designed to be used in conjunction with either the DM75491 and/or the DM8861 in driving eight common cathode LED digits operating in the multiplex mode of drive.

This circuit features eight separate high gain Darlington connected transistor circuits, see Figure 4f. Each Darlington transistor pair is capable of sinking 500 mA with a maximum collector to ground drop of 1.6V. Each collector can withstand

10V at a maximum leakage of 250 μ A in the off state. Maximum input current is 2.0 mA at 10V, making the circuit particularly well suited for direct drive from MOS circuits.

Figure 11 shows the DM8863 used in a typical 8-digit calculator application. The important feature of the DM8863 is the very high sink current capability. This allows multiplex operation of large digits or large numbers of digits without the use of discrete high current transistors.

Another application of the DM8863 is shown in Figure 12. In this case the DM8863 is used along with the MM4311/MM5311 series digital clock circuits in the implementation of a 6-digit clock display. Here the DM8863 is used as a segment driver for a common anode display. The use of the DM8863 in this manner replaces a total of 14 resistors and 7 transistors.

The DM8863 uses a single supply with a maximum voltage of 10V. Table II specifies the operating temperature range and package type for the DM8863.

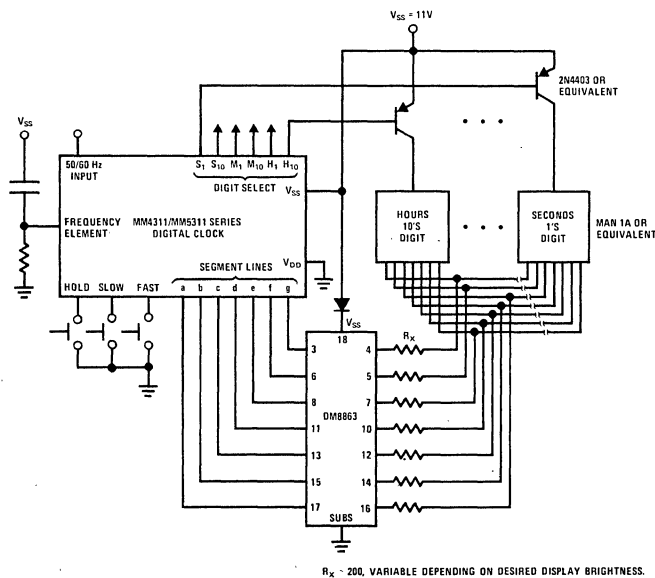


FIGURE 12. Digital Clock Using DM8863

DM8864, DM8865, DM8866 MOS TO LED DIGIT DRIVERS

The DM8864, DM8865, and DM8866 were designed to drive common cathode nine, eight, and seven digit displays respectively. The applications of these drivers are similar to those of the DM75492 and DM8863 except that operating current levels are lower.

All circuits feature maximum input current of 2.0 mA at a voltage of 6.5V. Output sink capability is 50 mA at a maximum collector to ground drop of 1.5V. Output leakage is 40 μ A (max) at an output voltage of 6.0V. All circuits operate from a supply that can vary from 5.0V to 9.5V.

DM8864 NINE DIGIT DRIVER

The DM8864 is a nine digit common cathode LED driver. Each package contains nine separate digit drivers. The circuit also features a "low battery" indicator driver which will light a decimal point whenever a 9.0V battery drops below 6.5V typical.

Figure 13 shows the DM8864 in a typical calculator drive application. The operating temperature range

and package type for the DM8864 is given in Table II.

DM8865 EIGHT DIGIT DRIVER

The DM8865 is an eight digit common cathode LED driver. Eight separate drivers are contained within each package. As with the DM8864 and DM8866 the DM8865 can also be used as a segment driver for common anode displays in the multiplex or nonmultiplex mode as long as the segment current does not exceed 50 mA.

Table II gives the operating temperature range and package type for the DM8865.

DM8866 SEVEN DIGIT DRIVER

The DM8866 is a seven digit common cathode LED driver. Each package contains seven separate digit drivers. Logic is also provided for a "low battery" indicator which will detect a 9.0V battery drop to below 6.5V typical and drive a decimal point.

Table II lists the package type and temperature range of the DM8866.

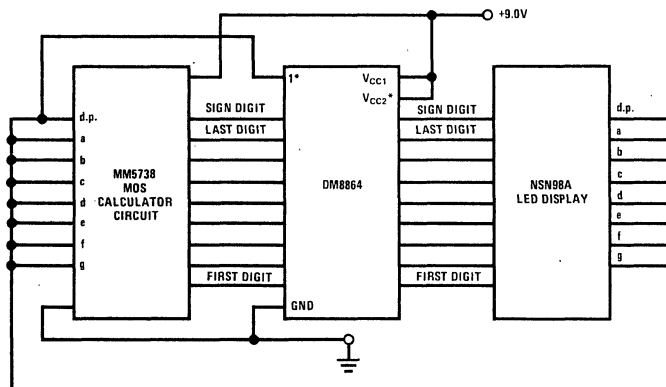


FIGURE 13. A Typical Application of the DM8864, Showing a Complete 8-Digit, 5 Function Calculator with Memory.



Section 6 Memory Support

6

TEMPERATURE RANGE		DESCRIPTION	PAGE NUMBER
- 55°C to + 125°C	0°C to + 70°C		
—	DS0025C	2-Phase PMOS Clock Driver	6-4
*DS0026	DS0026C	2-Phase PMOS Clock Driver	6-7
*DS0056	DS0056C	2-Phase PMOS Clock Driver	6-7
—	DS3245	Quad MOS Clock Driver	6-14
DS1617	DS3617	Bubble Memory Sense Amplifier	6-17
*DS1628	DS3628	Octal TRI-STATE MOS Driver	6-24
*DS1644	DS3644	Quad TTL-to-MOS Clock Drivers	6-27
*DS1674	DS3674	Quad TTL-to-MOS Clock Drivers	6-27
*DS1645	DS3645	Hex TRI-STATE TTL-to-MOS Latch/Drivers	6-30
*DS1675	DS3675	Hex TRI-STATE TTL-to-MOS Latch/Drivers	6-30
*DS1647	DS3647	Quad TRI-STATE I/O Registers	6-35
*DS1677	DS3677	Quad TRI-STATE I/O Registers	6-35
*DS16147	DS36147	Quad TRI-STATE I/O Registers	6-35
*DS16177	DS36177	Quad TRI-STATE I/O Registers	6-35
*DS1648	DS3648	TRI-STATE TTL-to-MOS Multiplexer/Driver	6-41
*DS1678	DS3678	TRI-STATE TTL-to-MOS Multiplexer/Driver	6-41
*DS1649	DS3649	Hex TRI-STATE TTL-to-MOS Driver	6-46
*DS1679	DS3679	Hex TRI-STATE TTL-to-MOS Driver	6-46
*DS1651	DS3651	Quad High Speed MOS Sense Amplifiers	6-49
*DS1653	DS3653	Quad High Speed MOS Sense Amplifiers	6-49
*DS1671	DS3671	Dual Bootstrapped 2-Phase Clock Driver	6-55
—	DS3685	Hex TRI-STATE Latch	6-59
*DS16149	DS36149	Hex MOS Drivers	6-62
*DS16179	DS36179	Hex MOS Drivers	6-62
*DS55325	DS75325	Memory Drivers	6-66
—	DS75361	Dual TTL-to-MOS Driver	6-73
—	DS75362	Dual TTL-to-MOS Driver	6-78
—	DS75365	Quad TTL-to-MOS Driver	6-83
—	AN-76	Applying Modern Clock Drivers to MOS Memories	6-88

*Also available screened in accordance with MIL-STD-883 Class B. Refer to National Semiconductor's "The Reliability Handbook".

4k & 16k N-CHANNEL MOS MEMORY INTERFACE CIRCUITS

Page No.	Device Number and Name	5V Clock Drivers	12V Clock Drivers	4k RAM Address Drivers	16k RAM Address Drivers	Data I/O	Timing & Control Drivers
6-17	DS3617 Bubble Memory Sense Amplifier						
6-24	DS3628 Octal TRI-STATE [®] MOS Driver	•			•		•
6-27	DS3644, DS3674 Quad MOS Clock Driver		•				
6-14	DS3245 Quad MOS Clock Driver		•				
6-30	DS3645, DS3675 Hex TRI-STATE MOS Driver Latch			•			
6-35	DS3647, DS3677, DS36147, DS36177 Quad TRI-STATE MOS Memory I/O Register					•	
6-41	DS3648, DS3678 TRI-STATE MOS Multiplexer/Driver	•		•	•		•
6-46	DS3649, DS3679 Hex TRI-STATE MOS Driver	•		•			•
6-59	DS3685 Hex TRI-STATE Latch						
6-62	DS36149, DS36179 Hex MOS Driver	•		•			•
6-66	DS75325 Memory Driver						
6-73	DS75361 Dual TTL-to-MOS Driver		•				
6-78	DS75362 Dual TTL-to-MOS Driver		•				
6-83	DS75365 Quad TTL-to-MOS Driver		•				
2-5	DP8303, DP8304B, DP8307, DP8308 8-Bit Bidirectional Transceiver					•	
8-11	DP8216, DP8226 4-Bit Bidirectional Transceiver					•	
2-89	DS8T26, DS8T28 Quad TRI-STATE Bus Driver					•	
8-4	DP8212 8-Bit Input/Output Port					•	

P-CHANNEL MOS INTERFACE CIRCUITS

FUNCTION	CHARACTERISTICS	TEMPERATURE		PAGE NO.
		0°C to +70°C	-55°C to +125°C	
Clock Driver	Dual, 30V, Drive 1000 pF @ 1 MHz	DS0025C		6-4
Clock Driver	Dual, 20V, Drive 1000 pF @ 5 MHz	DS0026C	DS0026	6-7
Clock Driver	Same as DS0026, May Use Pull-Up Resistor	DS0056C	DS0056	6-7
Clock Driver	Same as DS0026, May Be Bootstrapped	DS3671	DS1671	6-55
Differential Sense Amplifier	Quad TRI-STATE ±7 mV Sensitivity	DS3651	DS1651	6-49
Differential Sense Amplifier	Quad Open-Collector ±7 mV Sensitivity	DS3653	DS1653	6-49

Note. Refer to Application Note 76 for additional information on clock drivers.

DS0025C Two Phase MOS Clock Driver

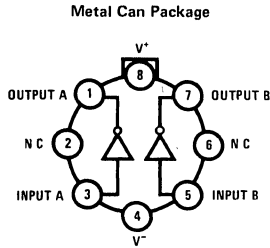
General Description

The DS0025C is a monolithic, low cost, two phase MOS clock driver that is designed to be driven by TTL line drivers or buffers such as the DS8830 or DM7440. Two input coupling capacitors are used to perform the level shift from TTL to MOS logic levels. Optimum performance in turn-off delay and fall time are obtained when the output pulse is logically controlled by the input. However, output pulse widths may be set by selection of the input capacitor eliminating the need for tight input pulse control.

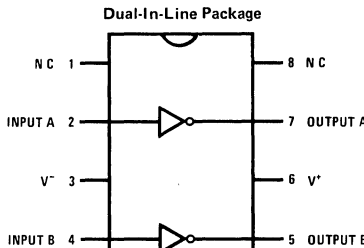
Features

- 8-lead TO-5 or 8-lead or 14-lead dual-in-line package
- High Output Voltage Swings—up to 30V
- High Output Current Drive Capability—up to 1.5A
- Rep. Rate: 1.0 MHz into > 1000 pF
- Driven by DS8830, DM7440
- "Zero" Quiescent Power

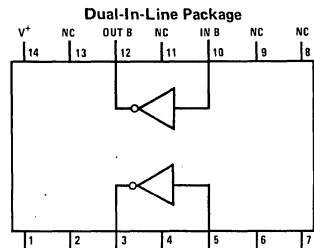
Connection Diagrams



Note: Pin 4 connected to case.
TOP VIEW



TOP VIEW



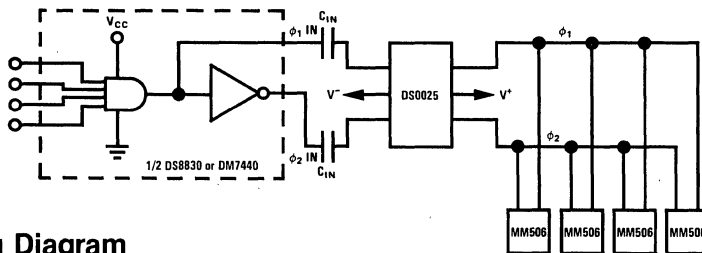
TOP VIEW

Order Number DS0025CH
See NS Package H08C

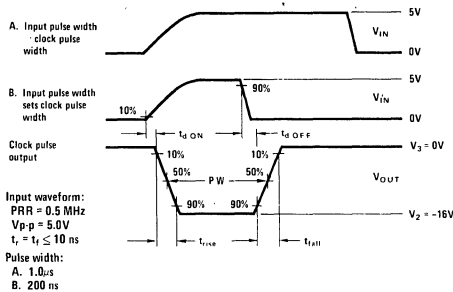
Order Number DS0025CN
or DS0025CJ-8
See NS Package N08A or J08A

Order Number DS0025CJ
See NS Package J14A

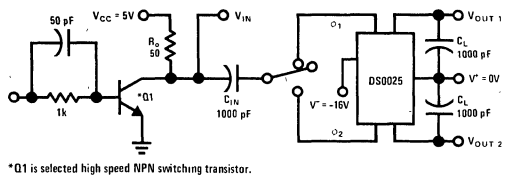
Typical Application



Timing Diagram



AC Test Circuit



*Q1 is selected high speed NPN switching transistor.

Absolute Maximum Ratings (Note 1)

(V ⁺ - V ⁻) Voltage Differential	30V
Input Current	100 mA
Peak Output Current	1.5A
Storage Temperature	-65°C to +150°C
Operating Temperature	0°C to +85°C
Lead Temperature (Soldering, 10 sec)	300°C

Maximum Power Dissipation* at 25°C

8-Pin Cavity Package	1150 mW
14-Pin Cavity Package	1410 mW
Molded Package	1080 mW
Metal Can (TO-5) Package	670 mW

*Derate 8-pin cavity package 7.8 mW/°C above 25°C; derate 14-pin cavity package 9.5 mW/°C above 25°C; derate molded package 8.7 mW/°C above 25°C; derate metal can (TO-5) package 4.5 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3) See test circuit.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{dON} Turn-On Delay Time	C _{IN} = 0.001μF, R _{IN} = 0Ω, C _L = 0.001μF		15	30	ns
t _{RISE} Rise Time	C _{IN} = 0.001μF, R _{IN} = 0Ω, C _L = 0.001μF		25	50	ns
t _{dOFF} Turn-Off Delay Time	C _{IN} = 0.001μF, R _{IN} = 0Ω, C _L = 0.001μF (Note 4)		30	60	ns
t _{FALL} Fall Time	C _{IN} = 0.001μF, R _{IN} = 0Ω, (Note 4)	60	90	120	ns
	C _L = 0.001μF (Note 5)	100	150	250	ns
PW Pulse Width (50% to 50%)	C _{IN} = 0.001μF, R _{IN} = 0Ω, C _L = 0.001μF (Note 5)		500		ns
V _{O+} Positive Output Voltage Swing	V _{IN} = 0V, I _{OUT} = -1 mA	V ⁺ -1.0	V ⁺ -0.7V		V
V _{O-} Negative Output Voltage Swing	I _{IN} = 10 mA, I _{OUT} = 1 mA		V ⁻ +0.7V	V ⁻ +1.5V	V

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS0025C.

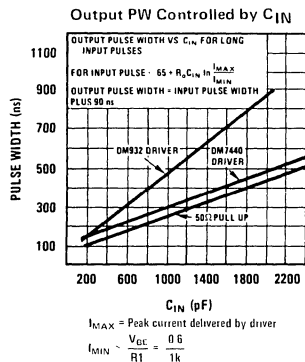
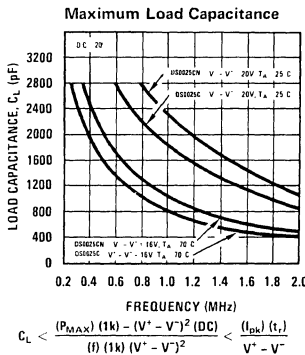
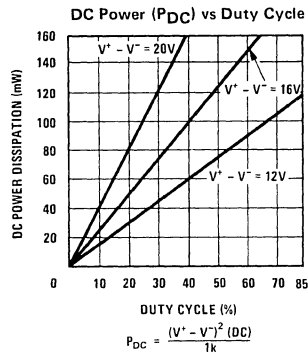
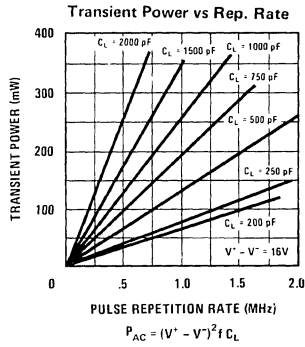
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Parameter values apply for clock pulse width determined by input pulse width.

Note 5: Parameter values for input pulse width greater than output clock pulse width.

6

Typical Performance



Applications Information (Reference AN-76)

Circuit Operation

Input current forced into the base of Q_1 through the coupling capacitor C_{IN} causes Q_1 to be driven into saturation, swinging the output to $V^- + V_{CE(sat)} + V_{Diode}$.

When the input current has decayed, or has been switched, such that Q_1 turns off, Q_2 receives base drive through R_2 , turning Q_2 on. This supplies current to the load and the output swings positive to $V^+ - V_{BE}$.

It may be noted that Q_1 must switch off before Q_2 begins to supply current, hence high internal transients currents from V^- to V^+ cannot occur.

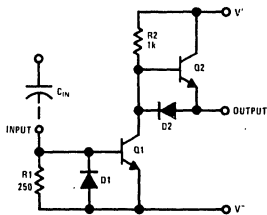


FIGURE 1. DS0025C Schematic (One-Half Circuit)

Fan-Out Calculation

The drive capability of the DS0025C is a function of system requirements, i.e. speed, ambient temperature, voltage swing, drive circuitry, and stray wiring capacity.

The following equations cover the necessary cal-

Example Calculation

How many MM506 shift registers can be driven by a DS0025CN driver at 1 MHz using a clock pulse width of 200 ns, rise time 30–50 ns and 16V amplitude over the temperature range 0–70°C?

Power Dissipation:

At 70°C the DS0025CN can dissipate 870 mW when soldered into printed circuit board.

Transient Peak Current Limitation:

From equation (1), it can be seen that at 16V and 30 ns, the maximum load that can be driven is limited to 2800 pF.

Average Internal Power:

Equation (3), gives an average power of 50 mW at 16V and a 20% duty cycle.

culations to enable the fan-out to be calculated for any system condition.

Transient Current

The maximum peak output current of the DS0025 is given as 1.5A. Average transient current required from the driver can be calculated from:

$$I = \frac{C_L (V^+ - V^-)}{t_r} \quad (1)$$

Typical rise times into 1000 pF load is 25 ns
For $V^+ - V^- = 20V$, $I = 0.8A$.

Transient Output Power

The average transient power (P_{ac}) dissipated, is equal to the energy needed to charge and discharge the output capacitive load (C_L) multiplied by the frequency of operation (f).

$$P_{AC} = C_L \times (V^+ - V^-)^2 \times f \quad (2)$$

For $V^+ - V^- = 20V$, $f = 1.0$ MHz, $C_L = 1000$ pF,
 $P_{AC} = 400$ mW.

Internal Power

"0" State Negligible (<3 mW)

"1" State

$$P_{int} = \frac{(V^+ - V^-)^2}{R_2} \times \text{Duty Cycle} \quad (3)$$

$$= 80 \text{ mW for } V^+ - V^- = 20V, \text{ DC} = 20\%$$

Package Power Dissipation

Total average power = transient output power + internal power

For one-half of the DS0025C, 870 mW \div 2 can be dissipated.

$$435 \text{ mW} = 50 \text{ mW} + \text{transient output power}$$

$$385 \text{ mW} = \text{transient output power}$$

Using equation (2) at 16V, 1 MHz and 350 mW, each half of the DS0025CN can drive a 1367 pF load. This is less than the load imposed by the transient current limitation of equation (1) and so a maximum load of 1367 pF would prevail.

From the data sheet for the MM506, the average clock pulse load is 80 pF. Therefore the number of devices driven is 1367/80 or 17 registers.

DS0026, DS0056 5 MHz Two Phase MOS Clock Drivers
General Description

DS0026/DS0056 are low cost monolithic high speed two phase MOS clock drivers and interface circuits. Unique circuit design provides both very high speed operation and the ability to drive large capacitive loads. The device accepts standard TTL outputs and converts them to MOS logic levels. They may be driven from standard 54/74 series and 54S/74S series gates and flip-flops or from drivers such as the DS8830 or DM7440. The DS0026 and DS0056 are intended for applications in which the output pulse width is logically controlled; i.e., the output pulse width is equal to the input pulse width.

The DS0026/DS0056 are designed to fulfill a wide variety of MOS interface requirements. As a MOS clock driver for long silicon-gate shift registers, a single device can drive over 10k bits at 5 MHz. Six devices provide input address and precharge drive for a 8k by 16-bit 1103 RAM memory system. Information on the correct usage of the DS0026 in these as well as other systems is included in the application note AN-76.

The DS0026 and DS0056 are identical except each driver in the DS0056 is provided with a V_{BB} connection to supply a higher voltage to the output stage. This aids

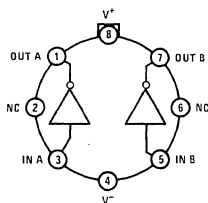
in pulling up the output when it is in the high state. An external resistor tied between these extra pins and a supply higher than V^+ will cause the output to pull up to $(V^+ - 0.1V)$ in the off state.

For DS0056 applications, it is required that an external resistor be used to prevent damage to the device when the driver switches low. A typical V_{BB} connection is shown on the next page.

These devices are available in 8-lead TO-5, one watt copper lead frame 8-pin mini-DIP, and one and a half watt ceramic DIP, and TO-8 packages.

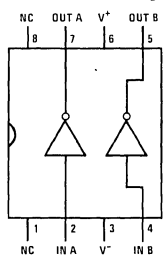
Features

- Fast rise and fall times—20 ns with 1000 pF load
- High output swing—20V
- High output current drive— ± 1.5 amps
- TTL compatible inputs
- High rep rate—5 to 10 MHz depending on power dissipation
- Low power consumption in MOS "0" state—2 mW
- Drives to 0.4V of GND for RAM address drive

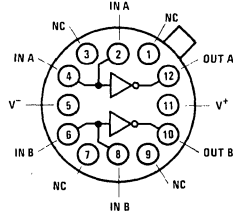
Connection Diagrams (Top Views)
TO-5 Package


Note: Pin 4 connected to case

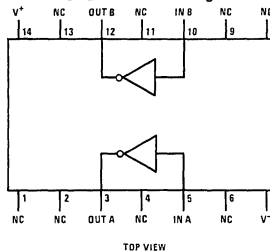
**Order Number DS0026H
or DS0026CH
See NS Package H08C**

Dual-In-Line Package


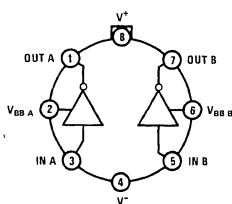
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DS0026CN or DS0026J-8
See NS Package J08A or N08A**

TO-8 Package


**Order Number DS0026G
or DS0026CG
See NS Package G12C**

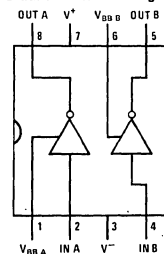
Dual-In-Line Package


**Order Number DS0026J
or DS0026CJ
See NS Package J14A**

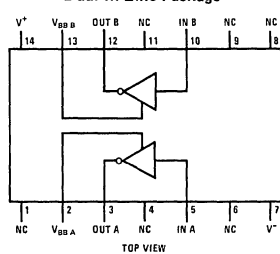
TO-5 Package


Note: Pin 4 connected to case.

**Order Number DS0056H
or DS0056CH
See NS Package H08C**

Dual-In-Line Package


**Order Number DS0056J-8,
DS0056CJ-8 or DS0056CN
See NS Package J08A or N08A**

Dual-In-Line Package


**Order Number DS0056J
or DS0056CJ
See NS Package J14A**

Absolute Maximum Ratings (Note 1)

$V^+ - V^-$ Differential Voltage	22V
Input Current	100 mA
Input Voltage ($V_{IN} - V^-$)	5.5V
Peak Output Current	1.5A
Maximum Power Dissipation* at 25°C	
Cavity Package (8-Pin)	1150 mW
Cavity Package (14-Pin)	1380 mW
Molded Package	1040 mW
Metal Can (TO-5) Package	660 mW

Operating Temperature Range	-55°C to +125°C
DS0026, DS0056	0°C to +70°C
DS0026C, DS0056C	-65°C to +150°C
Storage Temperature Range	300°C
Lead Temperature (Soldering, 10 seconds)	

*Derate 8-pin cavity package 7.7 mW/°C above 25°C; derate 14-pin cavity package 9.3 mW/°C above 25°C; derate molded package 8.4 mW/°C above 25°C; derate metal can (TO-5) package 4.4 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V_{IH}	Logic "1" Input Voltage	$V^- = 0V$	2	1.5	V	
I_{IH}	Logic "1" Input Current	$V_{IN} - V^- = 2.4V$	10	15	mA	
V_{IL}	Logic "0" Input Voltage	$V^- = 0V$	0.6	0.4	V	
I_{IL}	Logic "0" Input Current	$V_{IN} - V^- = 0V$	-3	-10	μA	
V_{OL}	Logic "1" Output Voltage	$V_{IN} - V^- = 2.4V$		$V^- + 0.7$	$V^+ + 1.0$	V
V_{OH}	Logic "0" Output Voltage	$V_{IN} - V^- = 0.4V, V_{BB} \geq V^+ + 1.0V$	DS0026	$V^+ - 1.0$	$V^+ - 0.7$	V
			DS0056	$V^+ - 0.3$	$V^+ - 0.1$	V
$I_{CC(ON)}$	"ON" Supply Current (one side on)	$V^+ - V^- = 20V, V_{IN} - V^- = 2.4V$ (Note 6)	DS0026	30	40	mA
			DS0056	12	30	mA
$I_{CC(OFF)}$	"OFF" Supply Current	$V^+ - V^- = 20V,$ $V_{IN} - V^- = 0V$	70°C	10	100	μA
			125°C	10	500	μA

Switching Characteristics ($T_A = 25^\circ C$) (Notes 5 and 7)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{ON}	Turn-on Delay	(Figure 1)	5	7.5	12	ns
		(Figure 2)		11		ns
t_{OFF}	Turn-off Delay	(Figure 1)		12	15	ns
		(Figure 2)		13		ns
t_r	Rise Time	(Figure 1), (Note 5)	$C_L = 500$ pF	15	18	ns
			$C_L = 1000$ pF	20	35	ns
		(Figure 2), (Note 5)	$C_L = 500$ pF	30	40	ns
			$C_L = 1000$ pF	36	50	ns
t_f	Fall Time	(Figure 1), (Note 5)	$C_L = 500$ pF	12	16	ns
			$C_L = 1000$ pF	17	25	ns
		(Figure 2), (Note 5)	$C_L = 500$ pF	28	35	ns
			$C_L = 1000$ pF	31	40	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: These specifications apply for $V^+ - V^- = 10V$ to $20V, C_L = 1000$ pF, over the temperature range of $-55^\circ C$ to $+125^\circ C$ for the DS0026, DS0056 and $0^\circ C$ to $+70^\circ C$ for the DS0026C, DS0056C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

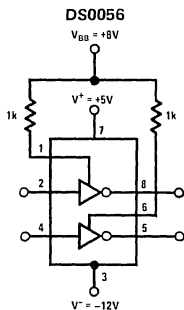
Note 4: All typical values for the $T_A = 25^\circ C$.

Note 5: Rise and fall time are given for MOS logic levels; i.e., rise time is transition from logic "0" to logic "1" which is voltage fall.

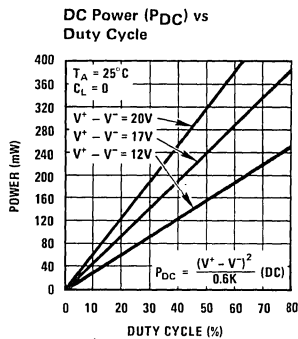
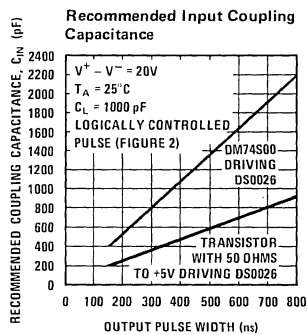
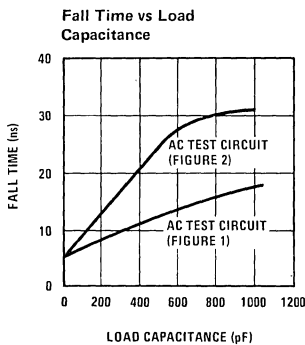
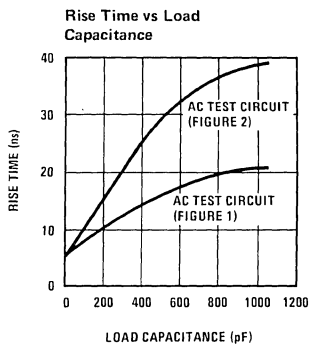
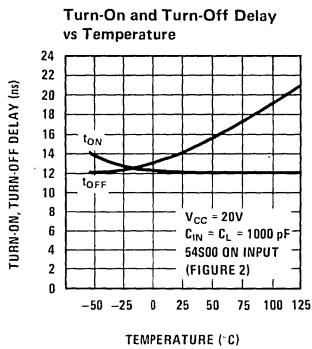
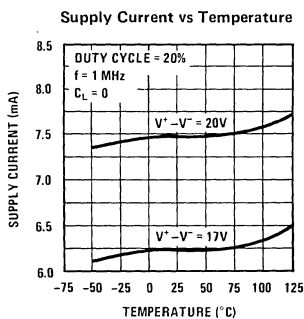
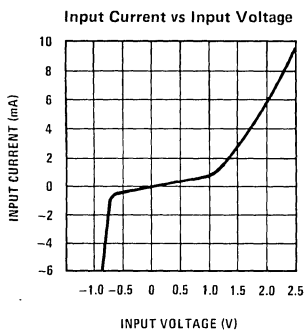
Note 6: I_{BB} for DS0056 is approximately $(V_{BB} - V^-)/1$ kΩ (for one side) when output is low.

Note 7: The high current transient (as high as 1.5A) through the resistance of the external interconnecting V^- lead during the output transition from the high state to the low state can appear as negative feedback to the input. If the external interconnecting lead from the driving circuit to V^- is electrically long, or has significant dc resistance, it can subtract from the switching response.

Typical V_{BB} Connection



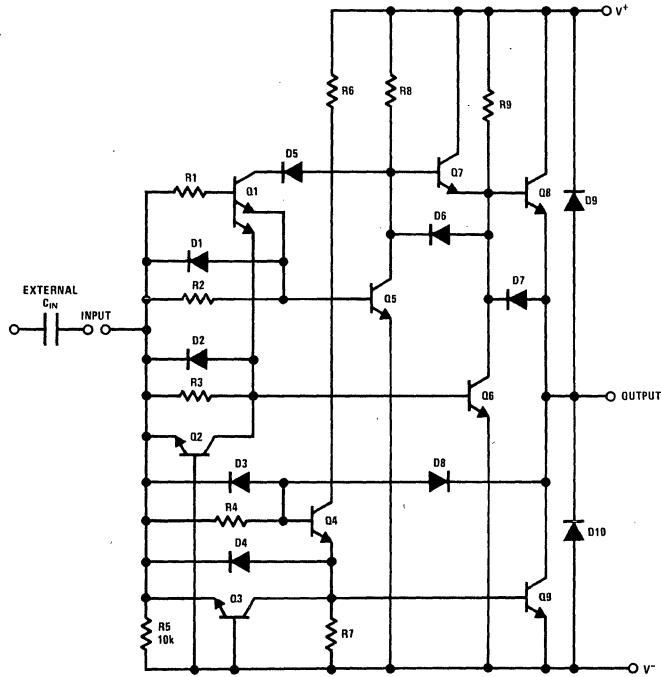
Typical Performance Characteristics



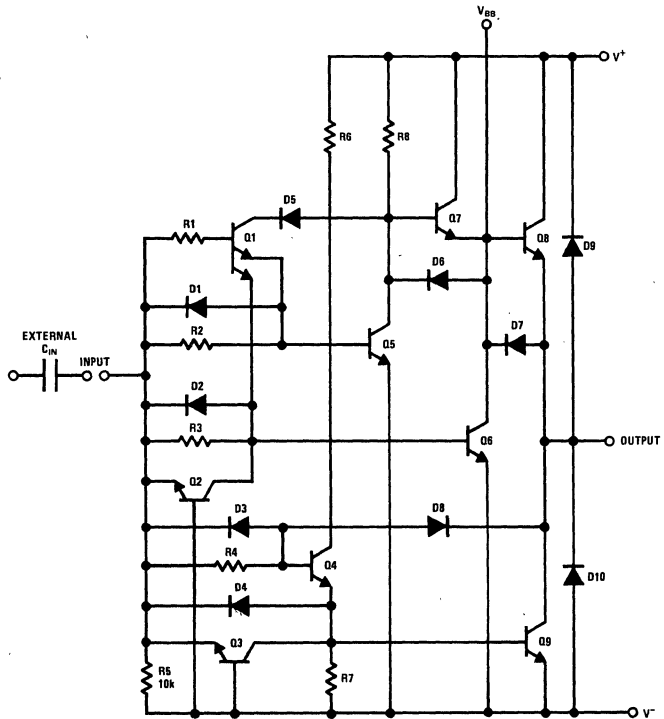
DS0026, DS0056

6

Schematic Diagrams



1/2 DS0026



1/2 DS0056

AC Test Circuits and Switching Time Waveforms

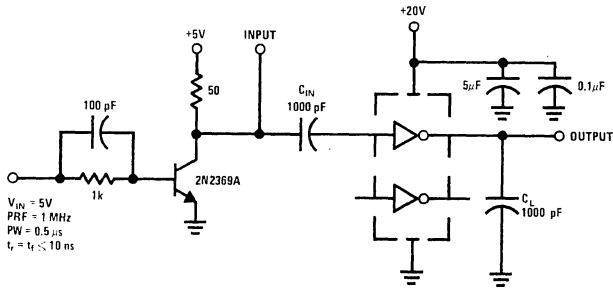


FIGURE 1.

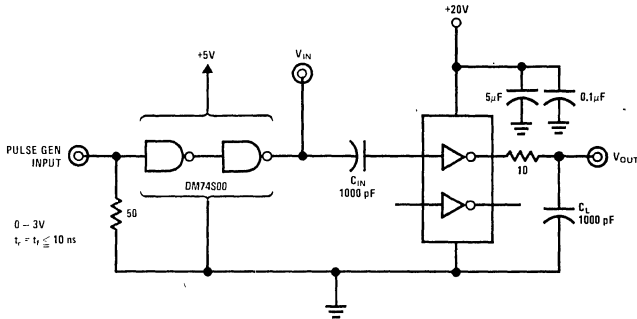
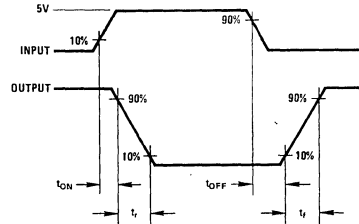
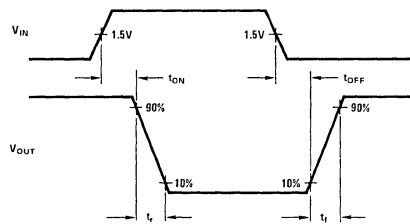
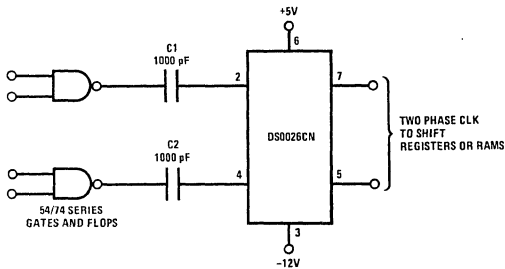


FIGURE 2.

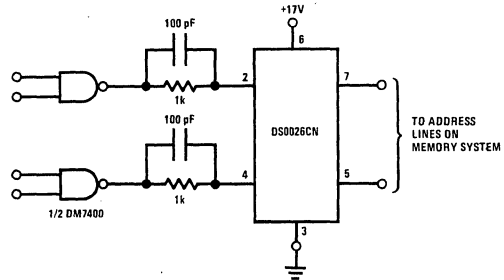


Typical Applications

AC Coupled MOS Clock Driver



DC Coupled RAM Memory Address or Precharge Driver (Positive Supply Only)



Application Hints

DRIVING THE MM5262 WITH THE DS0056 CLOCK DRIVER

The clock signals for the MM5262 have three requirements which have the potential of generating problems for the user. These requirements, high speed, large voltage swing and large capacitive loads, combine to provide ample opportunity for inductive ringing on clock lines, coupling clock signals to other clocks and/or inputs and outputs and generating noise on the power supplies. All of these problems have the potential of causing the memory system to malfunction. Recognizing the source and potential of these problems early in the design of a memory system is the most critical step. The object here is to point out the source of these problems and give a quantitative feel for their magnitude.

Line ringing comes from the fact that at a high enough frequency any line must be considered as a transmission line with distributed inductance and capacitance. To see how much ringing can be tolerated we must examine the clock voltage specification. *Figure 6* shows the clock

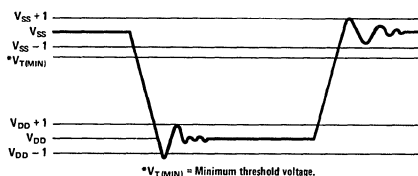


FIGURE 6. Clock Waveform

specification, in diagram form, with idealized ringing sketched in. The ringing of the clock about the V_{SS} level is particularly critical. If the $V_{SS} - 1$ V_{OH} is not maintained, at all times, the information stored in the memory could be altered. Referring to *Figure 1*, if the threshold voltage of a transistor were $-1.3V$, the clock going to $V_{SS} - 1$ would mean that all the devices, whose gates are tied to that clock, would be only 300 mV from turning on. The internal circuitry needs this noise margin and from the functional description of the RAM it is easy to see that turning a clock on at the wrong time can have disastrous results.

Controlling the clock ringing is particularly difficult because of the relative magnitude of the allowable ringing, compared to the magnitude of the transition. In this case it is 1V out of 20V or only 5%. Ringing can be controlled by damping the clock driver and minimizing the line inductance.

Damping the clock driver by placing a resistance in series with its output is effective, but there is a limit since it also slows down the rise and fall time of the clock signal. Because the typical clock driver can be much faster than the worst case driver, the damping resistor serves the useful function of limiting the minimum rise and fall time. This is very important because the faster the rise and fall times, the worse the ringing problem becomes. The size of the damping resistor varies because it is dependent on the details of the actual application. It must be determined empirically. In practice a resistance of 10 ohms to 20 ohms is usually optimum.

Limiting the inductance of the clock lines can be accomplished by minimizing their length and by laying out the lines such that the return current is closely coupled to the clock lines. When minimizing the length of clock lines it is important to minimize the distance from the clock driver output to the furthest point being driven. Because of this, memory boards are usually designed with clock drivers in the center of the memory array, rather than on one side, reducing the maximum distance by a factor of 2.

Using multilayer printed circuit boards with clock lines sandwiched between the V_{DD} and V_{SS} power planes minimizes the inductance of the clock lines. It also serves the function of preventing the clocks from coupling noise into input and output lines. Unfortunately multilayer printed circuit boards are more expensive than two sided boards. The user must make the decision as to the necessity of multilayer boards. Suffice it to say here, that reliable memory boards can be designed using two sided printed circuit boards.

The recommended clock driver for use with the MM4262/MM5262 is the DS0056/DS0056C dual clock driver. This device is designed specifically for use with dynamic circuits using a substrate, V_{BB} , supply. Typically it will drive a 1000 pF load with 20 ns rise and fall times. *Figure 7* shows a schematic of a single driver.

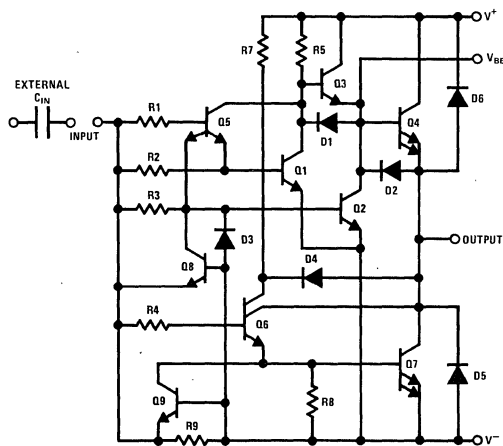


FIGURE 7. Schematic of 1/2 DS0056

In the case of the MM5262, V^+ is a +5V and V_{BB} is +8.5V. V_{BB} should be connected to the V_{BB} pin shown in *Figure 7* through a 1 k Ω resistor. This allows transistor Q4 to saturate, pulling the output to within a $V_{CE(SAT)}$ of the V^+ supply. This is critical because as was shown before, the $V_{SS} - 1.0V$ clock level must not be exceeded at any time. Without the V_{BB} pull up on the base of Q4 the output at best will be 0.6V below the V^+ supply and can be 1V below the V^+ supply reducing the noise margin or this line to zero.

Application Hints (Continued)

Because of the amount of current that the clock driver must supply to its capacitive load, the distribution of power to the clock driver must be considered. *Figure 8* gives the idealized voltage and current waveforms for a clock driver driving a 1000 pF capacitor with 20 ns rise and fall time.

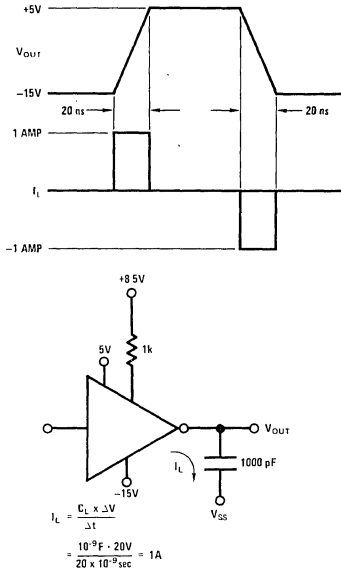


FIGURE 8. Clock Waveforms (Voltage and Current)

As can be seen the current is significant. This current flows in the V_{DD} and V_{SS} power lines. Any significant inductance in the lines will produce large voltage transients on the power supplies. A bypass capacitor, as close as possible to the clock driver, is helpful in minimizing this problem. This bypass is most effective when connected between the V_{SS} and V_{DD} supplies. A bypass capacitor for each DS0056 is recommended. The size of the bypass capacitor depends on the amount of capacitance being driven. Using a low inductance capacitor, such as a ceramic or silver mica, is most effective. Another helpful technique is to run the V_{DD} and V_{SS} lines, to the clock driver, adjacent to each other. This tends to reduce the lines inductance and therefore the magnitude of the voltage transients.

While discussing the clock driver, it should be pointed out that the DS0056 is a relatively low input impedance device. It is possible to couple current noise into the input without seeing a significant voltage. Since this noise is difficult to detect with an oscilloscope it is often overlooked.

Lastly, the clock lines must be considered as noise generators. *Figure 9* shows a clock coupled through a parasitic coupling capacitor, C_C , to eight data input lines being driven by a 7404. A parasitic lumped line

inductance, L , is also shown. Let us assume, for the sake of argument, that C_C is 1 pF and that the rise time of the clock is high enough to completely isolate the clock transient from the 7404 because of the inductance, L .

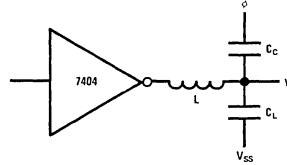


FIGURE 9. Clock Coupling

With a clock transition of 20V the magnitude of the voltage generated across C_L is:

$$V = 20V \times \frac{C_C}{C_L + C_C} = 20V \times \left(\frac{1}{56+1} \right) = 0.35V$$

This has been a hypothetical example to emphasize that with 20V low rise/fall time transitions, parasitic elements can not be neglected. In this example, 1 pF of parasitic capacitance could cause system malfunction, because a 7404 without a pull up resistor has typically only 0.3V of noise margin in the "1" state at 25°C. Of course it is stretching things to assume that the inductance, L , completely isolates the clock transient from the 7404. However, it does point out the need to minimize inductance in input/output as well as clock lines.

The output is current, so it is more meaningful to examine the current that is coupled through a 1 pF parasitic capacitance. The current would be:

$$I = C_C \times \frac{\Delta V}{\Delta t} = \frac{1 \times 10^{-12} \times 20}{20 \times 10^{-9}} = 1 \text{ mA}$$

This exceeds the total output current swing so it is obviously significant.

Clock coupling to inputs and outputs can be minimized by using multilayer printed circuit boards, as mentioned previously, physically isolating clock lines and/or running clock lines at right angles to input/output lines. All of these techniques tend to minimize parasitic coupling capacitance from the clocks to the signals in question.

In considering clock coupling it is also important to have a detailed knowledge of the functional characteristics of the device being used. As an example, for the MM5262, coupling noise from the $\phi 2$ clock to the address lines is of no particular consequence. On the other hand the address inputs will be sensitive to noise coupled from $\phi 1$ clock.

DS3245 Quad MOS Clock Driver

General Description

The DS3245 is a quad bipolar-to-MOS clock driver with TTL compatible inputs. It is designed to provide high output current and voltage capabilities necessary for optimum driving of high capacitance N-channel MOS memory systems.

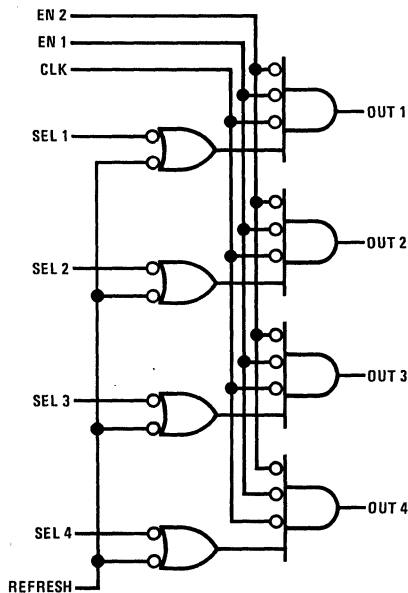
Only 2 supplies, 5 V_{DC} and 12 V_{DC}, are required without compromising the usual high V_{OH} specification obtained by circuits using a third supply.

The device features 2 common enable inputs, a refresh input, and a clock control input for simplified system designs. The circuit was designed for driving highly capacitive loads at high speeds and uses Schottky-clamped transistors. PNP transistors are used on all inputs, thereby minimizing input loading.

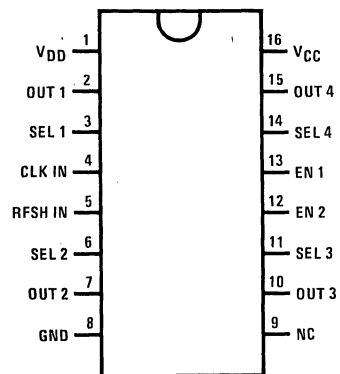
Features

- TTL compatible inputs
- Operates from 2 standard supplies: 5 V_{DC}, 12 V_{DC}
- Internal bootstrap circuit eliminates need for external PNP's
- PNP inputs minimize loading
- High voltage/current outputs
- Input and output clamping diodes
- Control logic optimized for use with MOS memory systems
- Pin and function equivalent to Intel 3245

Logic and Connection Diagrams



Dual-In-Line Package



TOP VIEW

Order Number DS3245J or DS3245N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Temperature Under Bias	-10°C to +85°C
Storage Temperature	-65°C to +150°C
Supply Voltage, V _{CC}	-0.5 to +7V
Supply Voltage, V _{DD}	-0.5 to +14V
All Input Voltages	-1.0 to V _{DD}
Outputs for Clock Driver	-1.0 to V _{DD} +1V
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Electrical Characteristics T_A = 0°C to +75°C, V_{CC} = 5V ±5%, V_{DD} = 12V ±5%

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
I _{FD}	Select Input Load Current	V _F = 0.45V			-0.25	mA
I _{FE}	Enable Input Load Current	V _F = 0.45V			-1.0	mA
I _{RD}	Select Input Leakage Current	V _R = 5V			10	μA
I _{RE}	Enable Input Leakage Current	V _R = 5V			40	μA
V _{OL}	Output Low Voltage	I _{OL} = 5 mA, V _{IH} = 2V			0.45	V
		I _{OL} = -5 mA	-1.0			V
V _{OH}	Output High Voltage	I _{OH} = -1 mA, V _{IL} = 0.8V	V _{DD} -0.50	/		V
		I _{OH} = 5 mA			V _{DD} +1.0	V
V _{IL}	Input Low Voltage, All Inputs				0.8	V
V _{IH}	Input High Voltage, All Inputs		2			V
V _{CLAMP}	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -12 mA		-1.0	-1.5	V

Power Supply Current Drain

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
I _{CC}	Current from V _{CC} Output in High State	V _{CC} = 5.25V, V _{DD} = 12.6V		26	34	mA
I _{DD}	Current from V _{DD} Output in High State	V _{CC} = 5.25V, V _{DD} = 12.6V		23	30	mA
I _{CC}	Current from V _{CC} Output in Low State	V _{CC} = 5.25V, V _{DD} = 12.6V		29	39	mA
I _{DD}	Current from V _{DD} Output in Low State	V _{CC} = 5.25V, V _{DD} = 12.6V		13	19	mA

Note 1: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Switching Characteristics $T_A = 0^\circ\text{C to } +75^\circ\text{C}$, $V_{CC} = 5\text{V} \pm 5\%$, $V_{DD} = 12\text{V} \pm 5\%$

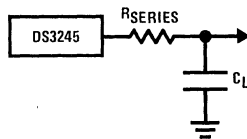
PARAMETER	CONDITIONS	MIN (Note 3)	TYP (Notes 4, 6)	MAX (Note 5)	UNITS
t_{L+}	Input to Output Delay	$R_{SERIES} = 0$	5	11	ns
t_{DR}	Delay Plus Rise Time	$R_{SERIES} = 0$	20	32	ns
t_{L-}	Input to Output Delay	$R_{SERIES} = 0$	3	7	ns
t_{DF}	Delay Plus Fall Time	$R_{SERIES} = 0$	18	32	ns
t_T	Output Transition Time	$R_{SERIES} = 20\Omega$	10	17	ns
t_{DR}	Delay Plus Rise Time	$R_{SERIES} = 20\Omega$	27	38	ns
t_{DF}	Delay Plus Fall Time	$R_{SERIES} = 20\Omega$	25	38	ns

Capacitance $T_A = 25^\circ\text{C}$ (Note 7)

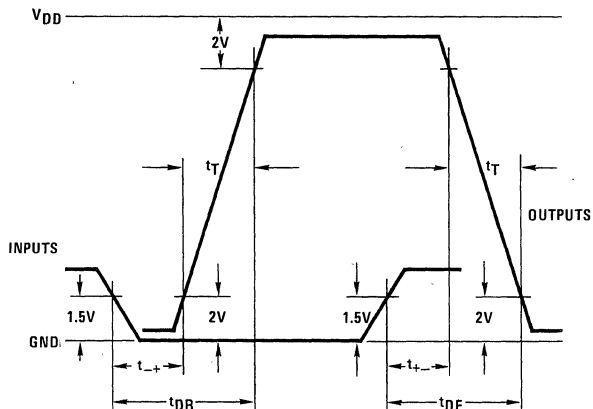
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
C_{IN}	Input Capacitance, $\bar{I}1, \bar{I}2, \bar{I}3, \bar{I}4$		5	8	pF
C_{IN}	Input Capacitance, $\bar{R}, \bar{C}, \bar{E}1, \bar{E}2$		8	12	pF

- Note 3: $C_L = 150\text{ pF}$
 - Note 4: $C_L = 200\text{ pF}$
 - Note 5: $C_L = 250\text{ pF}$
- These values represent a range of total stray plus clock capacitance for nine 4k RAMs.
- Note 6: Typical values are measured at 25°C .
- Note 7: This parameter is periodically sampled and is not 100% tested. Condition of measurement is $f = 1\text{ MHz}$, $V_{BIAS} = 2\text{V}$, $V_{CC} = 0\text{V}$, and $T_A = 25^\circ\text{C}$.

AC Test Circuit and Switching Time Waveforms



Input pulse amplitudes: 3V
 Input pulse rise and fall times:
 5 ns between 1V and 2V
 Measurement points: see waveforms



DS1617/DS3617 Bubble Memory Sense Amplifier

General Description

The DS1617 and the DS3617 are bubble memory sense amplifiers that convert low level signals from magneto-resistive detectors of the bubble memory into TTL compatible output levels. Internal functions consist of an input bias circuit, an internally AC coupled amplifier, a high speed precision comparator, two flip-flops, a TRI-STATE[®] output stage and a power fail detector.

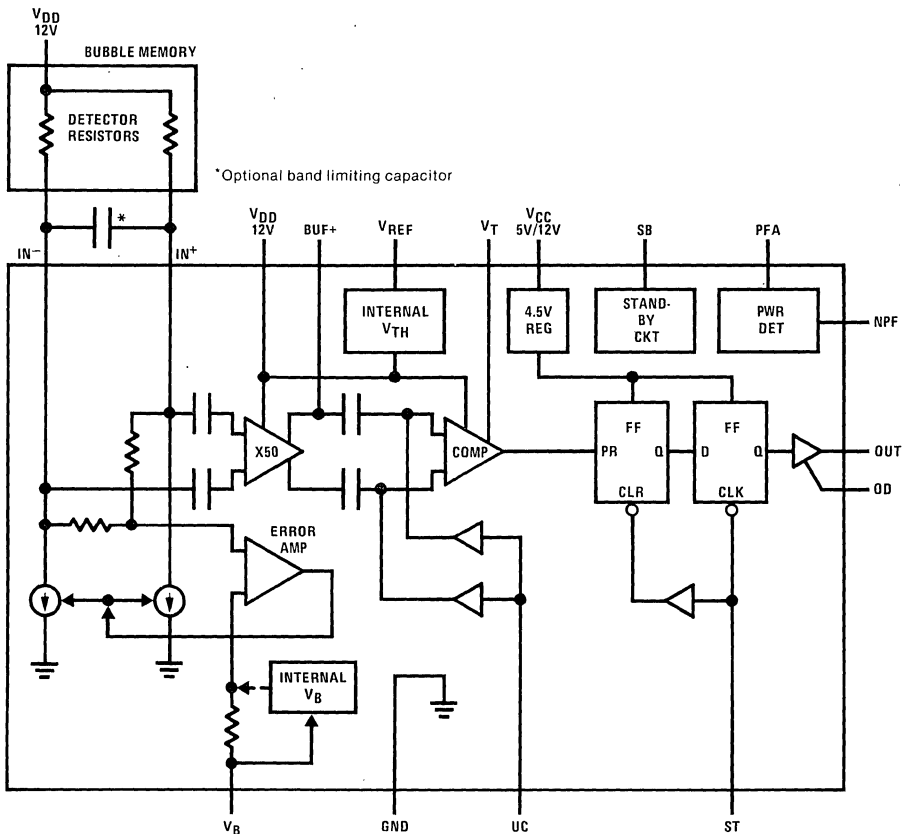
TTL compatible control inputs allow either average-to-peak or the conventional clamp and strobe (peak-to-peak) sensing of the input signal. The threshold voltage and the input bias voltage are externally adjustable allowing compatibility with different types of bubble memories.

Although specifically designed for bubble memory interfacing, they are easily adaptable for any application requiring detection of mV level signals in the 25 kHz to 4 MHz range. Typical application areas include fiber optic receivers, plated wire memory sense amplifiers and pulse discriminators.

Features

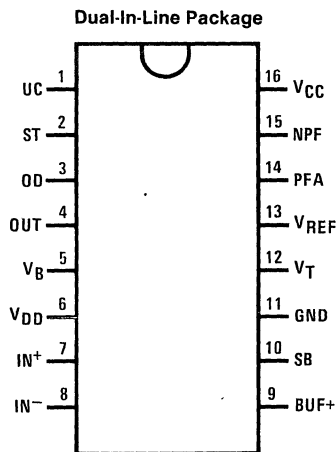
- Single 12V or 12V/5V operation
- On-chip adjustable detector bias circuit
- Choice of average-to-peak or clamp and strobe sensing
- Guaranteed tight threshold limits over the specified temperature and supply voltage range
- Threshold externally adjustable over 0 mV to 20 mV range (typical)
- On-chip reference for a 3.2 mV threshold (typical)
- TRI-STATE output
- No offset nulling requirement due to on-chip AC coupling at the input
- Power fail detector with adjustable trip level senses both supplies
- Compatible with a wide range of bubble memories
- Standard 16-pin dual-in-line package

Block Diagram



TRI-STATE[®] is a registered trademark of National Semiconductor Corp.

Connection Diagram



TOP VIEW

Order Number DS1617J,
DS3617J or DS3617N

See NS Package J16A or N16A

Functional Pin Description

ANALOG INPUTS

Differential Analog Inputs (IN^+ and IN^-): These are high impedance inputs for bubble memory detectors. They also provide the bias current to the detectors at a constant DC voltage. The sense-amp threshold is positive with respect to the IN^+ input.

Bias Voltage Input (V_B): When an external DC voltage (between 4V and 8V) is applied to this input, the internal error amplifier will adjust the bias current sources to maintain the average common-mode voltage of IN^+ and IN^- inputs at this value. This input can be connected to V_{DD} to obtain an internally set bias voltage of 7V typical. This voltage is derived on-chip from a resistor divider connected across the V_{DD} supply.

Threshold Adjust Input (V_T): An externally applied DC voltage in the range of 0V to 10V at this input will set the threshold of the sense-amplifier in the 0 mV to 20 mV range. The threshold is linearly related to this voltage.

Power Fail Adjust Input (PFA): The trip voltage of 5V and 12V supplies can be set to a fraction of their nominal values by applying an external reference voltage to this input (see graph). When precise power fail detection is not required this input may be grounded to obtain a trip voltage between 35% and 65% of the nominal supply levels (i.e., 5V and 12V).

ANALOG OUTPUTS

Buffered Bubble Signal Output (BUF+): This is the preamplifier output which is in phase with the IN^+ input.

It provides an amplified version of the input differential signal (X_{25}) at a low impedance for monitoring purposes.

Internal Reference for V_T (V_{REF}): This output, when connected to V_T input, provides a threshold of 3.2 mV typical. This voltage is derived on the chip from a potential divider connected across the V_{DD} supply. When V_B is also derived in the same fashion, the threshold will track the amplitude variations of the bubble signal resulting from the V_{DD} supply variations.

DIGITAL INPUTS

Unclamp Input (UC): A logic low level on this input causes clamping of the differential inputs of the comparator to a common voltage. When a logic high level is applied, the inputs are unclamped within a few nanoseconds (5 ns typ). The capacitive coupling of the preamplifier outputs to the inputs of the comparator enables referencing of the threshold to any point on the input waveform by using this input. This pin is shorted to V_{CC} or V_{DD} when the average-to-peak sensing method is used.

Strobe Input (ST): A high-to-low transition of this input causes the transfer of data from an internal latch to the output flip-flop. As long as this input is low the internal latch cannot be set by the comparator. For clamp and strobe sensing, this input can be tied to the unclamp input and used as a single UC/ST control line.

Output Disable (OD): A logic high level at this input causes the data output to go into the high impedance state (TRI-STATE).

Standby Input (SB): When the sense-amp is not in use this input can be used to reduce power consumption. A logic high level applied to this input puts the sense-amp in standby mode and TRI-STATes the data output pin. The power fail detector circuit is not affected by this input.

DIGITAL OUTPUTS

Data Output (OUT): This output is high for signals crossing the threshold and low for those below the threshold. The data on this pin is valid a short time after the negative transition of the strobe signal and will remain valid until the next negative transition of the strobe signal.

Power Fail Detect Output (NPF): This output goes low when either one or both of the supplies fall below the trip voltage. It will remain low until both of the supplies fall below a minimum level which is 4V for V_{DD} and 2.8V for V_{CC} . It is an open collector output with an internal pull-up of 5 k Ω (typical). The circuit is insensitive to transients on the supplies and will typically reject a 500 ns pulse that goes 1V below the trip voltage.

POWER SUPPLIES

Analog Supply (V_{DD}): 12V.

Digital Supply (V_{CC}): 5V to 12V. This supply is internally regulated to 4.5V and hence can be tied to V_{DD} for single supply operation, but a standard 5V logic supply reduces power consumption and also permits power fail detection of the 5V supply.

Absolute Maximum Ratings (Note 1)

Supply Voltages (V_{DD} , V_{CC})	14V
Input Voltages	
Sense Inputs (IN^+ , IN^-)	14V
V_T Input	14V
V_{BIAS} Input (V_B)	14V
Control Inputs (UN, ST, OD, SB)	14V
PFA Input	5.5V
Output Voltage	5.5V
Storage Temperature	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1635 mW
Molded Package	1687 mW
Lead Temperature (Soldering, 10 seconds)	300°C

* Derate cavity package 10.9 mW/°C above 25°C; derate molded package 13.5 mW/°C above 25°C.

Recommended Operating Conditions

	Min	Max	Units
V_{DD} Supply Voltage			
DS1617	10.8	13.2	V
DS3617	11.4	12.6	V
V_{CC} Supply Voltage			
DS1617	4.5	13.2	V
DS3617	4.75	12.6	V
Temperature (T_A)			
DS1617	-55	125	°C
DS3617	0	70	°C
PFA Input Voltage	0	1.5	V
V_{BIAS} Input Voltage (V_B)	0	13.2	V
V_T Input Voltage (V_T) (Threshold Adjust)	-0.25	10	V
Sense Input Common-Mode Voltage (V_{CM})	4	8	V
Input Bias Current (I_B) (Into IN^+ and IN^- Inputs)	0.1	10	mA

DC Electrical Characteristics (Notes 2 and 3)

Parameter		Conditions		Min	Typ	Max	Units
ANALOG INPUTS AND OUTPUTS							
V_{IB}	Input Bias Voltage (at IN^+ and IN^- Inputs)	Internal (Note 4)	I_B in mA	Typ -0.15	0.588 V_{DD} + 0.01 I_B	Typ +0.15	V
		External (Note 5)	I_B in mA	Typ -0.1	V_B + 0.01 I_B	Typ +0.1	
ΔV_{IB} (temp)	Input Bias Voltage Variation with Temperature (IN^+ and IN^- Inputs)	$I_B = 5$ mA					
		-55°C < T_A < 125°C (DS1617)			±10		mV
		0°C < T_A < 70°C (DS3617)			±5		mV
I_{VT}	Input Current for V_T Input	$V_T = 0V$ to 5V			-1	-10	µA
I_{VB}	Input Current for V_B Input	$V_B = 4V$ to 8V			-2	-10	µA
V_{REF}	Internal Reference Voltage			0.98 Typ	0.125 V_{DD}	1.02 Typ	V
ΔV_{TP} (temp) (V_{CC} , V_{DD})	Temperature Variation of Power Fail Threshold	Set by V_{PFA} (See Graphs)					
		-55°C < T_A < 125°C (DS1617)			±0.6		%
		0°C < T_A < 70°C (DS3617)			±0.2		%
DIGITAL OUTPUTS (OUT, NPF)							
V_{OH}	Logical "1" Output Voltage	OUT	$OD = 0.8V$, $SB = 0.8V$, $I_{OH} = -400$ µA	2.4	2.8		V
		NPF	$I_{OH} = -100$ µA	2.4	3.8		
V_{OL}	Logical "0" Output Voltage	OUT	$OD = 0.8V$, $SB = 0.8V$, $I_{OL} = 10$ mA		0.4	0.5	V
		NPF	$V_{CC} = 4V$, $V_{DD} = 10V$, $V_{PFA} = 1.5V$, $I_{OL} = 5$ mA		0.35	0.5	
I_{OS}	Output Short Circuit Current	$V_O = 0V$, $V_{CC} = V_{DD} = \text{Max}$					mA
		OUT	$OD = 0.8V$, $SB = 0.8V$	-10	-20	-50	
		NPF	$V_{PFA} = 0V$	-0.5	-1	-1.5	
I_{OD}	TRI-STATE Output Current	OUT Only	$OD = 2.0V$, $SB = 0.8V$ or $OD = 0.8V$, $SB = 2.0V$	$V_O = 0.4V$		-100	µA
				$V_O = 4.0V$		100	
I_{PS}	Output Sink Current on NPF Output During Power Fail	$V_O = 0.5V$, $V_{PFA} = 1.5V$		$V_{CC} = 0V$	1	6	mA
				$V_{DD} = 4V$			
				$V_{CC} = 2.8V$	1	6	
				$V_{DD} = 0V$			
CONTROL INPUTS (UC, ST, OD, SB)							
V_{IH}	Logical "1" Input Voltage			2			V
V_{IL}	Logical "0" Input Voltage					0.8	V
I_{IH}	Logical "1" Input Current	$V_{IN} = 4V$				20	µA
I_{IL}	Logical "0" Input Current	$V_{IN} = 0.4V$				-200	µA
POWER SUPPLY CURRENTS							
I_{DDA}	Active V_{DD} Supply Current	$SB = 0.8V$			25	45	mA
I_{CCA}	Active V_{CC} Supply Current	$SB = 0.8V$			10	20	
I_{DDS}	Standby V_{DD} Supply Current	$SB = 2.0V$			12	25	
I_{CCS}	Standby V_{CC} Supply Current	$SB = 2.0V$			2	4	

AC Electrical Characteristics (Note 2)

Parameter	Conditions	Min	Typ	Max	Units		
SENSE INPUT CHARACTERISTICS							
V_{TH}	Differential Input Threshold Voltage	$V_B = 7V$ See Figure 5 for Test Waveforms		$0.97 \times Typ$ -0.0005	$0.00213 \times V_T$	$1.03 \times Typ$ $+0.0005$	V
V_{TR}	Threshold Adjustment Range	DS1617		0 to 8	-0.5 to 20		mV
		DS3617		0 to 10	-0.5 to 20		mV
f_{BW}	Preamp Bandwidth	@ ± 3 dB, $V_B = 7V$, $-55^\circ C < T_A < 125^\circ C$			0.025 to 4		MHz
		@ ± 0.1 dB, $V_B = 7V$, $-55^\circ C < T_A < 125^\circ C$			0.1 to 1		
R_{IN}	Differential Input Resistance			150			k Ω
C_{IN}	Differential Input Capacitance			12			pF
$\Delta V_{TH (temp)}$	Threshold Variation with Temperature	$V_{DD} = 12V$	$-55^\circ C < T < 125^\circ C$ (DS1617)		± 0.1		mV
			$0^\circ C < T < 70^\circ C$ (DS3617)		± 0.05		mV
T_{PC}	Effective Time Constant of Preamp AC Couplings	(From Sense Input to Comparator Inputs) UC = 3V			6		μs
T_{CL}	Clamp Circuit Time Constant	(Time Constant Associated with the Comparator Inputs when UC = 3V)			12		μs
TIMING REQUIREMENTS							
t_d	Delay Time, UC or ST Input High to Sense Input High	Figure 2		50			ns
t_s	Data Set-Up Time, Sense Input High to UC or ST Input Low	Figure 2		100			ns
t_{pwi}	Minimum Input Pulse Width at Threshold	Figure 2		100			ns
t_{pws}	Minimum Strobe Pulse Width	Figure 2		30			ns
t_{ON}	Power-Up Time from SB Low to Full Operation					100	μs
t_{OFF}	Power-Down Time from SB High to Reduced Power					1	μs
SWITCHING CHARACTERISTICS							
t_p	ST Input Low to Valid Data at the Output	Figures 1 and 3, OD = 0.8V, $C_L = 30$ pF, R1 = 5k, R2 = 1k			30	50	ns
TRI-STATE DELAYS FROM OD TO OUT							
t_{LZ}	Output Low to TRI-STATE	Figures 1 and 4 $C_L = 15$ pF, R1 = 1k, R2 = 1k			15	35	ns
t_{HZ}	Output High to TRI-STATE				15	35	ns
t_{ZL}	Output TRI-STATE to Active Low				15	40	ns
t_{ZH}	Output TRI-STATE to Active High				15	40	ns

Note 1: "Absolute maximum ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" and "Recommended Operating Conditions" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the supply and temperature range listed in the table of "Recommended Operating Conditions". All typical values are for $V_{CC} = 12V$, $V_{CC} = 5V$ and $T_A = 25^\circ C$ unless otherwise specified.

Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: V_B pin tied to V_{DD} .

Note 5: V_B pin connected to the external bias voltage.

Example Threshold Calculations

1. Find external voltage V_T to be applied for a 5 mV typical threshold. What is this tolerance of this threshold?

$$V_{TH}(typ) = 0.00213 \times V_T = 0.005V$$

$$\text{Therefore, } V_T = 0.005 / 0.00213 = 2.347V$$

$$V_{TH}(min) = 0.97 \times 0.005 - 0.0005 = 4.35 \text{ mV}$$

$$V_{TH}(max) = 1.03 \times 0.005 + 0.0005 = 5.65 \text{ mV}$$

$$\text{Hence, } V_{TH} = 5 \pm 0.65 \text{ mV}$$

$$\text{and Tolerance} = \pm 0.65 \text{ mV}$$

2. Find V_{TH} and its tolerance for $V_{DD} = 12V$ when internal reference (V_{REF}) is used for V_T .

$$V_T(yp) = V_{REF}(typ) = 0.125 \times V_{DD} = 1.5V$$

$$V_T(min) = V_{REF}(min) = 0.98 \times 1.5 = 1.47V$$

$$V_T(max) = V_{REF}(max) = 1.02 \times 1.5 = 1.53V$$

$$V_{TH}(typ) = 0.00213 \times V_T(yp) = 3.20 \text{ mV}$$

$$V_{TH}(min) = 0.97 \times 0.00213 \times V_T(min) - 0.0005 = 2.54 \text{ mV}$$

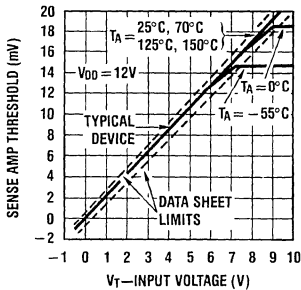
$$V_{TH}(max) = 1.03 \times 0.00213 \times V_T(max) + 0.0005 = 3.86 \text{ mV}$$

$$\text{Hence, } V_{TH} = 3.20 \pm 0.66 \text{ mV}$$

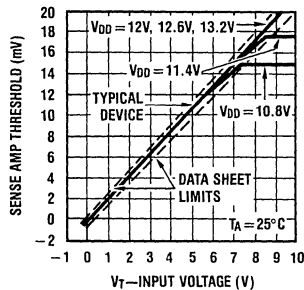
Note. Since V_{REF} is directly related to V_{DD} , the V_{TH} will follow the supply variations. But as long as the input bias voltage V_B is also derived in the same way (i.e., using a potential divider across V_{DD}), the threshold will track the amplitude changes in the bubble detector signal resulting from the V_{DD} supply variations.

Performance Characteristics

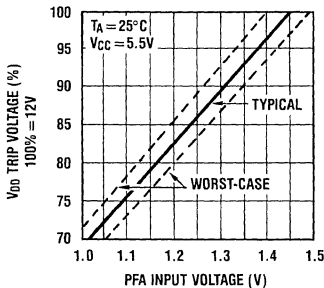
Threshold Transfer Function at Various Temperatures



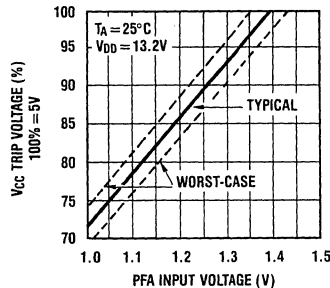
Threshold Transfer Function at Various Supply Voltages



Power Fail Trip Voltage Transfer Function for V_{DD}



Power Fail Trip Voltage Transfer Function for V_{CC}



AC Test Circuit and Switching Time Waveforms

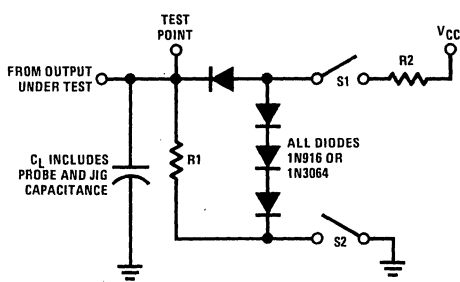


FIGURE 1. Output Load Circuit

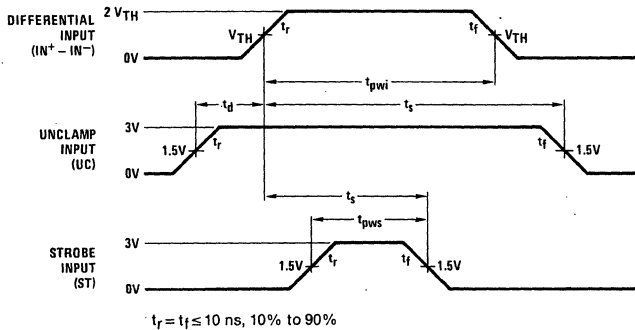


FIGURE 2. Delay, Set-Up and Hold Times

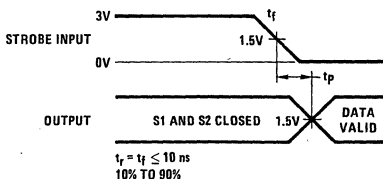
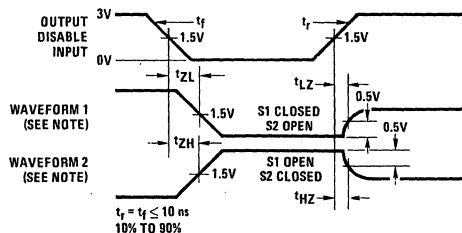
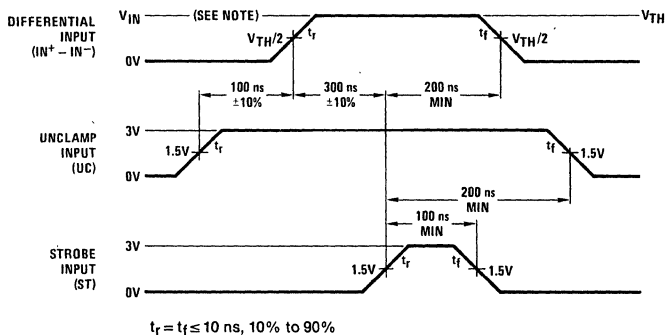


FIGURE 3. Propagation Delay from Strobe Input to Output



Note. Waveform 1 shows the output with internal conditions such that the output is low except when disabled by the output disable input. Waveform 2 shows the output with internal conditions such that the output is high except when disabled by the output disable input.

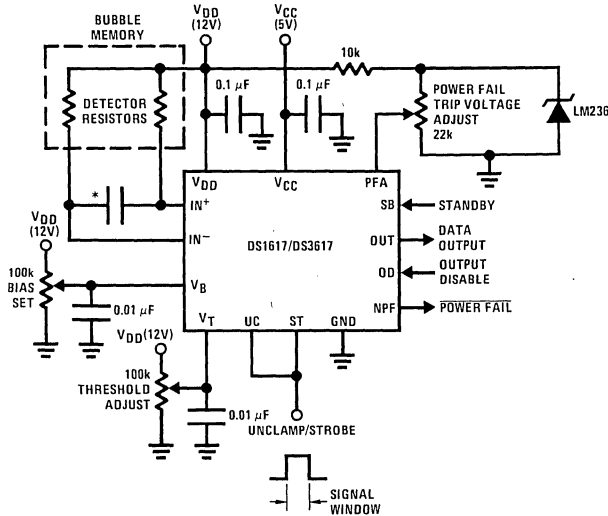
FIGURE 4. Propagation Delay from Output Disable to Output



Note. To determine the sense amplifier threshold, the input signal amplitude, V_{IN} , is varied around the set threshold value, V_{TH} , while monitoring the OUT pin on a scope. When V_{IN} is close to the threshold, the output will switch between Logic 0 and Logic 1 due to the noise on the input signal. The mid value of the threshold can be determined by adjusting V_{IN} to obtain equal brightness of high (V_{OH}) and low (V_{OL}) level output traces on the scope. In the above set-up, the signal is strobed after a 300 ns delay to allow for any overshoot or transients to settle. This method results in accurate threshold measurement that is relatively independent of input signal rise time. But due to AC coupling of the preamp, with an effective time constant of $6 \mu s$, the signal at the input of the comparator droops by 5% in 300 ns, which has to be accounted for. Hence, $V_{TH} = V_{IN} \times 0.95$.

FIGURE 5. Sense Input Threshold Measurement

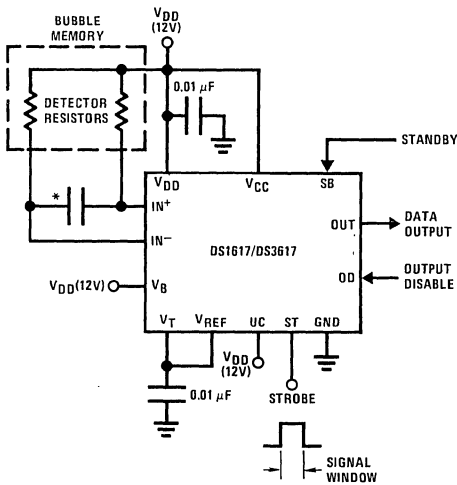
Bubble Memory Sense Amplifier with Adjustable Threshold and Bias Voltage



Note. The control inputs are set up for clamp-strobe or peak-to-peak sensing
 *Optional band limiting capacitor

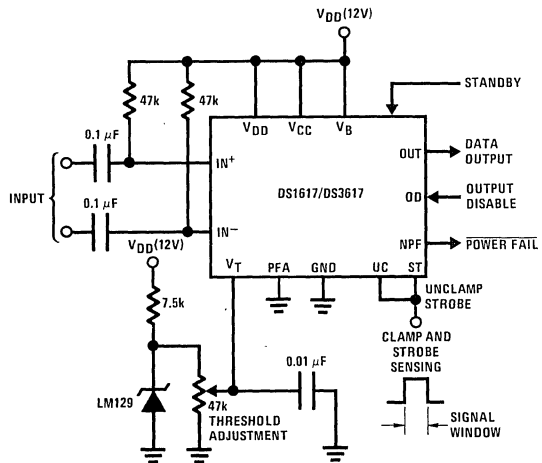
6

Bubble Memory Sense Amplifier with Internally Set Threshold (3 mV typ) and Input Bias Voltage (7V typ)



Note. The control inputs are set up for average-to-peak sensing
 *Optional band limiting capacitor

A General Purpose Precision Sense Amplifier with the Threshold Controlled by an External Reference



DS1628/DS3628 Octal TRI-STATE® MOS Drivers

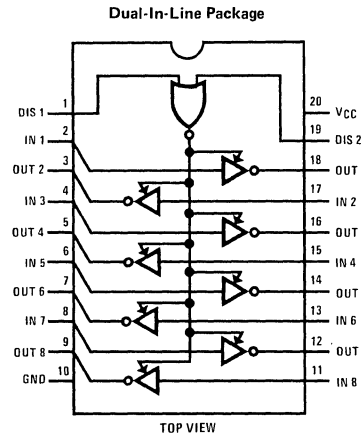
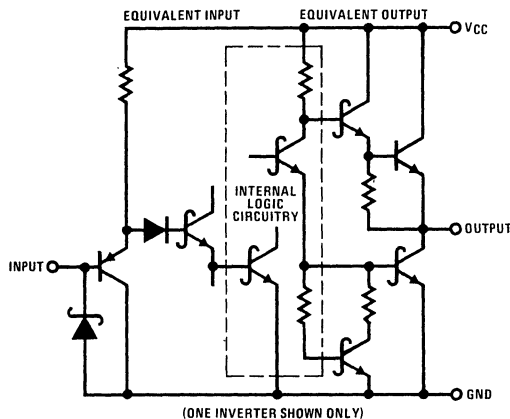
General Description

The DS1628/DS3628 are octal Schottky memory drivers with TRI-STATE® outputs designed to drive high capacitive loads associated with MOS memory systems. The drivers' output (V_{OH}) is specified at 3.4V to provide additional noise immunity required by MOS inputs. A PNP input structure is employed to minimize input currents. The circuit employs Schottky-clamped transistors for high speed. A NOR gate of two inputs, DIS1 and DIS2, controls the TRI-STATE mode.

Features

- High speed capabilities
 - typ 5 ns driving 50 pF & 8 ns driving 500 pF
- TRI-STATE outputs
- High V_{OH} (3.4 V min)
- High density
 - eight drivers and two disable controls for TRI-STATE in a 20-pin package
- PNP inputs reduce DC loading on bus lines
- Glitch-free power up/down

Schematic and Connection Diagrams



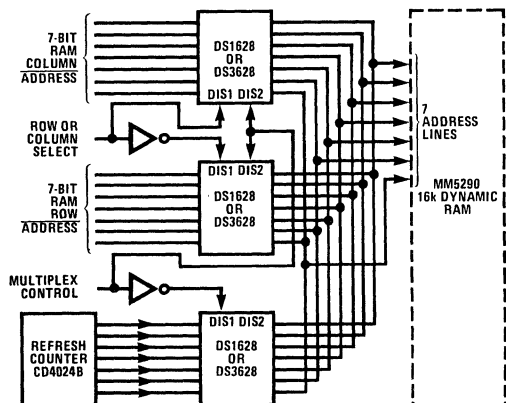
Order Number
 DS1628J, DS3628J, DS3628N
 See NS Package J20A or N20A

Truth Table

Disable Input		Input	Output
DIS 1	DIS 2		
H	H	X	Z
H	X	X	Z
X	H	X	Z
L	L	H	L
L	L	L	H

H = high level
 L = low level
 X = don't care
 Z = high impedance (off)

Typical Application



Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Logical "1" Input Voltage	7.0V
Logical "0" Input Voltage	-1.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1667 mW
Molded Package	1832 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 11.1 mW/°C above 25°C; derate molded package 14.7 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	4.5	5.5	V
Temperature (T _A)			
DS1628	-55	+125	°C
DS3628	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
V _{IN(1)}	Logical "1" Input Voltage			2.0			V
V _{IN(0)}	Logical "0" Input Voltage					0.8	V
I _{IN(1)}	Logical "1" Input Current	V _{CC} = 5.5V	V _{IN} = 5.5V		0.1	40	μA
I _{IN(0)}	Logical "0" Input Current	V _{CC} = 5.5V	V _{IN} = 0.5V		-180	-400	μA
V _{CLAMP}	Input Clamp Voltage	V _{CC} = 4.5V	I _{IN} = -18mA		-0.7	-1.2	V
V _{OH}	Logical "1" Output Voltage (No Load)	V _{CC} = 4.5V	I _{OH} = -10μA	DS1628	3.4	4.3	V
				DS3628	3.5	4.3	V
V _{OL}	Logical "0" Output Voltage (No Load)	V _{CC} = 4.5V	I _{OL} = 10μA	DS1628		0.25	0.4
				DS3628		0.25	0.35
V _{OH}	Logical "1" Output Voltage (With Load)	V _{CC} = 4.5V	I _{OH} = -1.0mA	DS1628	2.5	3.9	V
				DS3628	2.7	3.9	V
V _{OL}	Logical "0" Output Voltage (With Load)	V _{CC} = 4.5V	I _{OL} = 20mA	DS1628/DS3628		0.35	0.5
I _{ID}	Logical "1" Drive Current	V _{CC} = 4.5V	V _{OUT} = 0V (Note 6)		-150		mA
I _{OD}	Logical "0" Drive Current	V _{CC} = 4.5V	V _{OUT} = 4.5V (Note 6)		150		mA
Hi-Z	TRI-STATE Output Current	V _{OUT} = 0.4V to 2.4V DIS1 or DIS2 = 2.0V		-40	0.1	40	μA
I _{CC}	Power Supply Current	V _{CC} = 5.5V	One DIS Input = 3.0V All other Inputs = X, Outputs at Hi-Z		90	120	mA
			DIS1, DIS2 = 0V, others = 3V Outputs on		70	100	mA
			All Inputs = 0V, Outputs off		25	50	mA

Switching Characteristics (V_{CC} = 5V, T_A = 25°C) (Note 6)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
t _{S+}	Storage Delay Negative Edge	(Figure 1)	C _L = 50pF		4.0	5.0	ns
			C _L = 500pF		6.5	8.0	ns
t _{S-}	Storage Delay Positive Edge	(Figure 1)	C _L = 50pF		4.2	5.0	ns
			C _L = 500pF		6.5	8.0	ns
t _F	Fall Time	(Figure 1)	C _L = 50pF		4.2	6.0	ns
			C _L = 500pF		19	22	ns
t _R	Rise Time	(Figure 1)	C _L = 50pF		5.2	7.0	ns
			C _L = 500pF		20	24	ns
t _{ZL}	Delay from Disable Input to Logical "0" Level (from High Impedance State)	C _L = 50pF to GND	R _L = 2kΩ to V _{CC} (Figure 2)	19	25	ns	
t _{ZH}	Delay from Disable Input to Logical "1" Level (from High Impedance State)	C _L = 50pF to GND	R _L = 2kΩ to GND (Figure 2)	13	20	ns	
t _{LZ}	Delay from Disable Input to High Impedance State (from Logical "0" Level)	C _L = 50pF to GND	R _L = 400Ω to V _{CC} (Figure 3)	18	25	ns	
t _{HZ}	Delay from Disable Input to High Impedance State (from Logical "1" Level)	C _L = 50pF to GND	R _L = 400Ω to GND (Figure 3)	8.5	15	ns	

AC Test Circuits and Switching Time Waveforms

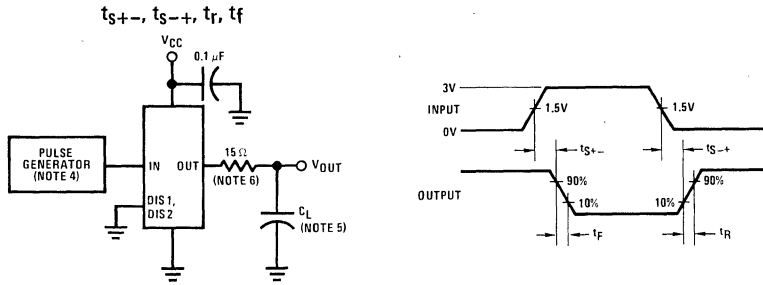


FIGURE 1

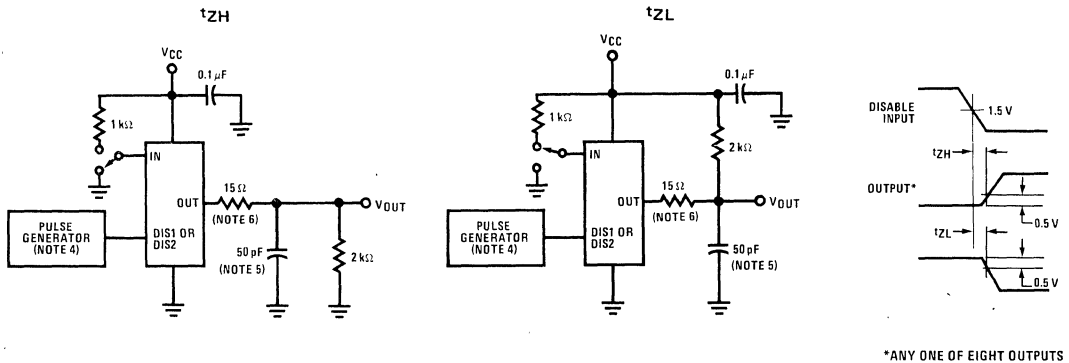


FIGURE 2

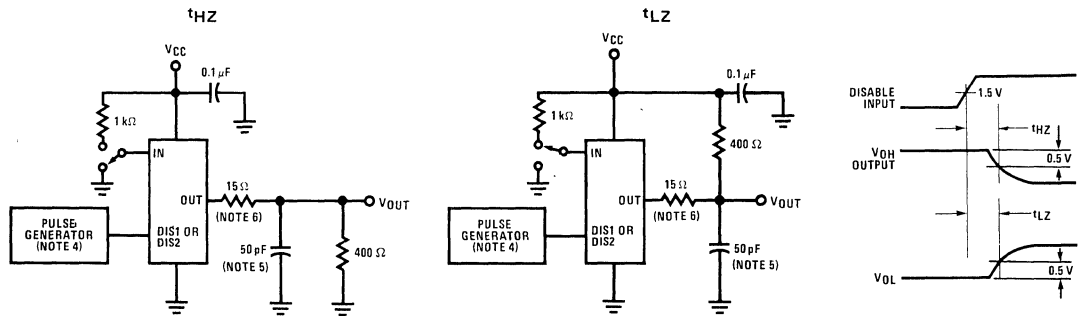


FIGURE 3

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the -55°C to $+125^{\circ}\text{C}$ temperature range for the DS1628 and across the 0°C to $+70^{\circ}\text{C}$ range for the DS3628. All typical values are for $T_A = 25^{\circ}\text{C}$ and $V_{CC} = 5\text{V}$.

Note 3: All currents into device pins shown as positive; all currents out of device pins shown as negative; all voltages references to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: The pulse generator has the following characteristics: $Z_{OUT} = 50\ \Omega$ and $PRR \leq 1\ \text{MHz}$. Rise and fall times between 10% and 90% points $\leq 5\ \text{ns}$.

Note 5: C_L includes probe and jig capacitance.

Note 6: When measuring output drive current and switching response for the DS1628 and DS3628 a $15\ \Omega$ resistor should be placed in series with each output.

DS1644/DS3644, DS1674/DS3674 Quad TTL to MOS Clock Drivers

General Description

The DS1644/DS3644 and DS1674/DS3674 are quad bipolar-to-MOS clock drivers with TTL compatible inputs. They are designed to provide high output current and voltage capabilities necessary for optimum driving of high capacitance N-channel MOS memory systems.

The device features two common enable inputs, a refresh input, and a clock control input for simplified system designs. The circuit was designed for driving highly capacitive loads at high speeds and uses Schottky-clamped transistors. PNP transistors are used on all inputs thereby minimizing input loading.

The circuit may be connected to provide a 12V clock output amplitude as required by 4k RAMs or a 5V clock output amplitude as required by 16k RAMs.

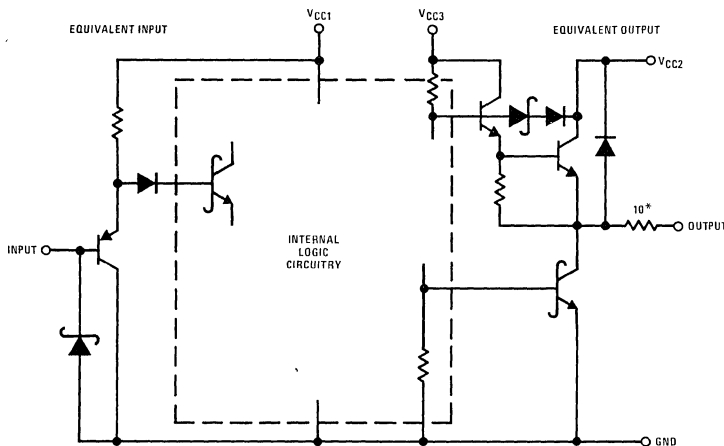
The DS1644/DS3644 contains a 10Ω resistor in series with each output to dampen the transients caused by the fast-switching output, while the DS1674/DS3674

has a direct, low impedance output for use with or without an external damping resistor.

Features

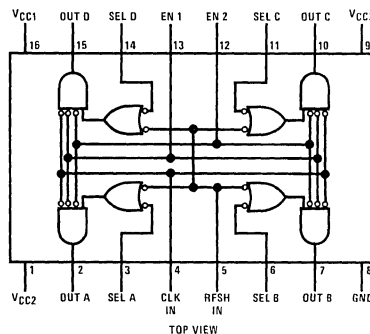
- TTL compatible inputs
- 12V clock or 5V clock driver
- Operates from standard bipolar and MOS supplies
- PNP inputs minimize loading
- High voltage/current outputs
- Input and output clamping diodes
- Control logic optimized for use with MOS memory systems
- Pin and function compatible with MC3460 and 3235
- Built-in damping resistors (DS1644/DS3644)

Schematic and Connection Diagrams



* DS1644/DS3644 only

Dual-In-Line Package



TOP VIEW

Order Number DS3644J, DS3674J,
DS3644N or DS3674N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	
V _{CC1}	7V
V _{CC2}	13.5V
V _{CC3}	16V
Input Voltage	-1.0V to +7V
Output Voltage	-1.0V to +16V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage			
V _{CC1}			
DS1644, DS1674	4.5	5.5	V
DS3644, DS3674	4.75	5.25	V
V _{CC2}			
DS1644, DS1674	4.5	13.2	V
DS3644, DS3674	4.75	12.6	V
V _{CC3}			
DS1644, DS1674	V _{CC2}	16.5	V
DS3644, DS3674	V _{CC2}	15.75	V
Temperature, T _A			
DS1644, DS1674	-55	+125	°C
DS3644, DS3674	0	+70	°C

Electrical Characteristics

5V operation, (V_{CC1} = V_{CC2} = 5V, V_{CC3} = 12V); 12V operation, (V_{CC1} = 5V, V_{CC2} = 12V, V_{CC3} = V_{CC2} + (3V ±10%)); DS1644, DS1674, ±10% power supply tolerances; DS3644, DS3674, ±5% power supply tolerances, unless otherwise noted. (Notes 2, 3 and 4).

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH}	Logical "1" Input Voltage	2			V	
V _{IL}	Logical "0" Input Voltage			0.8	V	
I _{IH}	Logical "1" Input Current	V _{IN} = 5.5V	Select Inputs All Other Inputs	0.01 0.04	10 40	μA
I _{IL}	Logical "0" Input Current	V _{IN} = 0.4V	Select Inputs All Other Inputs	-40 -0.16	-250 -1.0	μA
V _{CD}	Input Clamp Voltage	I _I = -12 mA		-0.8	-1.5	V
V _{OH}	Logical "1" Output Voltage	I _{OH} = -1 mA, V _{IL} = 0.8V	V _{CC2} -0.5	V _{CC2} -0.2		V
V _{OL}	Logical "0" Output Voltage	I _{OL} = 5 mA, V _{IH} = 2.0V		0.3	0.5	V
V _{OC}	Output Clamp Voltage	I _{OC} = 5 mA, V _{IL} = 0.8V		V _{CC2} +0.8	V _{CC2} +1.5	V
I _{CCH}	Supply Current Output High	All Inputs V _{IN} = 0V Outputs Open	V _{CC1} = Max	18	27	mA
I _{CC1}			12V Operation	-2	-4	mA
I _{CC2}				2	4	mA
I _{CC3}			5V Operation	-8	-16	mA
I _{CC2}				8	16	mA
I _{CCL}	Supply Currents Outputs Low	All Inputs V _{IN} = 5V Outputs Open	V _{CC1} = 5.25V	25	40	mA
I _{CC1}			V _{CC2} = 12.6V		3	mA
I _{CC2}			V _{CC3} = 15.75V	16	25	mA
I _{CC3}						

Switching Characteristics T_A = 25°C unless otherwise noted, (Note 4), (Figures 1, 2, 3 and 4)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t _{s-}	Storage Delay Negative Edge	R _D = 10 Ω	C _L = 100 pF	8	11	ns
			C _L = 400 pF	12	16	ns
t _{s+}	Storage Delay Positive Edge	R _D = 10 Ω	C _L = 100 pF	10	13	ns
			C _L = 400 pF	13	16	ns
t _F	Fall Time	R _D = 10 Ω	C _L = 100 pF	9	16	ns
			C _L = 400 pF	17	24	ns
t _R	Rise Time	R _D = 10 Ω	C _L = 100 pF	8	12	ns
			C _L = 400 pF	13	19	ns
t _{pd0}	Propagation Delay to a Logical "0"	R _D = 10 Ω	C _L = 100 pF	17	27	ns
			C _L = 400 pF	29	40	ns
t _{pd1}	Propagation Delay to a Logical "1"	R _D = 10 Ω	C _L = 100 pF	18	25	ns
			C _L = 400 pF	26	35	ns

Notes

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to $+125^{\circ}\text{C}$ temperature range for the DS1644, DS1674 and across the 0°C to $+70^{\circ}\text{C}$ range for the DS3644, DS3674. All typicals are given for $T_A = 25^{\circ}\text{C}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: For AC measurements, a 10Ω resistor must be placed in series with the output of the DS1674/DS3674. This resistor is internal to the DS1644/DS3644 and need not be added.

AC Test Circuits and Switching Time Waveforms

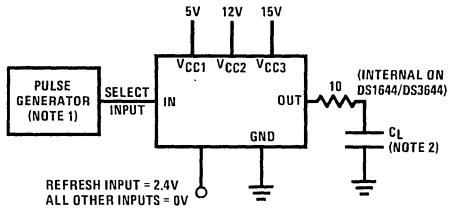


FIGURE 1. 12V Operation

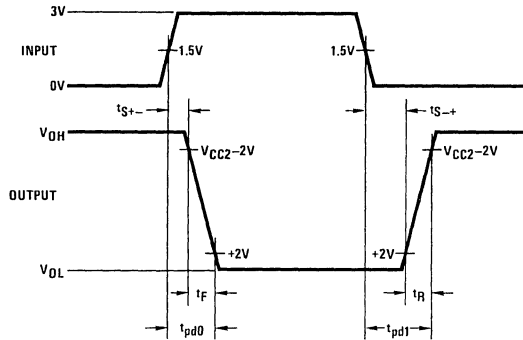


FIGURE 2. 12V Operation

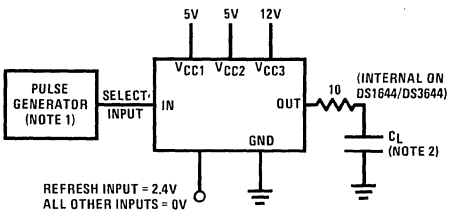


FIGURE 3. 5V Operation

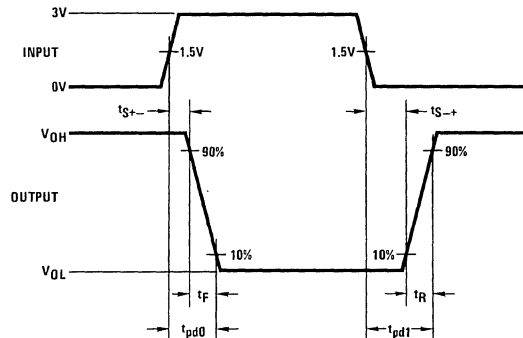


FIGURE 4. 5V Operation

Note 1: The pulse generator has the following characteristics. PPR = 1 MHz, $t_R \leq 10$ ns, $Z_{OUT} = 50\Omega$.

Note 2: C_L includes probe and jig capacitance.

Truth Table

INPUT					OUTPUT
ENABLE 1	ENABLE 2	SELECT INPUT	CLOCK INPUT	REFRESH INPUT	
1	X	X	X	X	0
X	1	X	X	X	0
X	X	X	1	X	0
X	X	1	X	1	0
0	0	0	0	X	1
0	0	X	0	0	1

DS1645/DS3645, DS1675/DS3675 Hex TRI-STATE® TTL to MOS Latches/Drivers

General Description

The DS1645/DS3645 and DS1675/DS3675 are hex MOS latches/drivers with outputs designed to drive large capacitive loads up to 500 pF associated with MOS memory systems. PNP input transistors are used to reduce input currents, allowing the large fan-out to these drivers needed in memory systems. The circuit has Schottky-clamped transistor logic for minimum propagation delay, and TRI-STATE® outputs which allow bus operation.

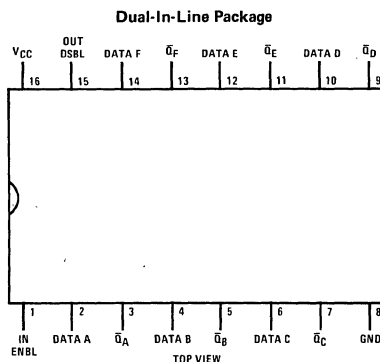
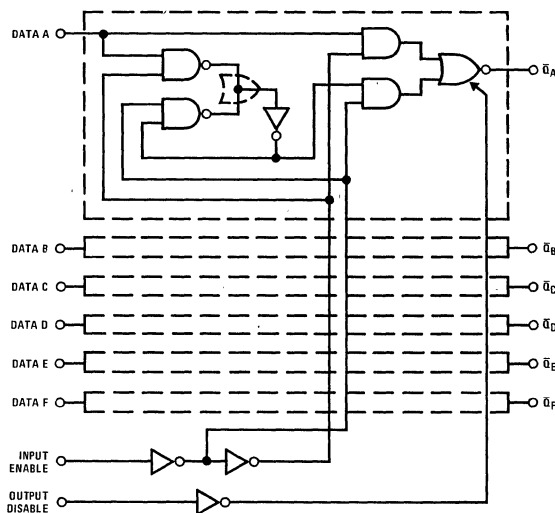
The DS1645/DS3645 has a 15 Ω resistor in series with the outputs to dampen transients caused by the fast switching output circuit. The DS1675/DS3675 has a direct, low impedance output for use with or without an external resistor.

The circuit employs a fall-through-latch which captures the data in parallel with the output, thereby eliminating the delay normally encountered in other latch circuits. The DS1645/DS3645 and DS1675/DS3675 may be used for input address lines or input/output data lines of a MOS memory system.

Features

- TTL compatible inputs
- PNP inputs minimize loading
- Capacitance-driving outputs
- TRI-STATE outputs
- Built-in damping resistor (DS1645/DS3645)

Logic and Connection Diagrams



Order Number DS1645J, DS1675J, DS3645J,
DS3675J, DS3645N or DS3675N
See NS Package J16A or N16A

Truth Table

INPUT ENABLE	OUTPUT DISABLE	DATA	OUTPUT	OPERATION
1	0	1	0	Data Feed-Through
1	0	0	1	Data Feed-Through
0	0	X	Q	Latched to Data Present when Enable Went Low
X	1	X	Hi-Z	High Impedance Output

X = Don't care
Hi-Z = TRI-STATE mode



Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7V
Logical "1" Input Voltage	7V
Logical "0" Input Voltage	-1.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	4.5	5.5	V
Temperature (T_A)			
DS1645, DS1675	-55	+125	°C
DS3645, DS3675	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
$V_{IN(1)}$	Logical "1" Input Voltage		2.0			V	
$V_{IN(0)}$	Logical "0" Input Voltage				0.8	V	
$I_{IN(1)}$	Logical "1" Input Current	$V_{IN} = 5.5V$ $V_{CC} = 5.5V$	Enable Inputs		0.1	40	μA
			Data Inputs		0.2	80	μA
$I_{IN(0)}$	Logical "0" Input Current	$V_{IN} = 0.5V$ $V_{CC} = 5.5V$	Enable Inputs		-50	-250	μA
			Data Inputs		-100	-500	μA
V_{CLAMP}	Input Clamp Voltage		$V_{CC} = 4.5V, I_{IN} = -18 mA$		-0.75	-1.2	V
V_{OH}	Logical "1" Output Voltage (No Load)	$V_{CC} = 4.5V, I_{OH} = -10 \mu A$	DS1645, DS1675	2.7	3.6		V
			DS3645, DS3675	2.8	3.6		V
V_{OL}	Logical "0" Output Voltage (No Load)	$V_{CC} = 4.5V, I_{OL} = 10 \mu A$	DS1645, DS1675	0.25	0.4		V
			DS3645, DS3675	0.25	0.35		V
V_{OH}	Logical "1" Output Voltage (With Load)	$V_{CC} = 4.5V, I_{OH} = -1.0 mA$	DS1645	2.4	3.5		V
			DS1675	2.5	3.5		V
			DS3645	2.6	3.5		V
			DS3675	2.7	3.5		V
V_{OL}	Logical "0" Output Voltage (With Load)	$V_{CC} = 4.5V, I_{OL} = 20 mA$	DS1645	0.6	1.1		V
			DS1675	0.4	0.5		V
			DS3645	0.6	1.0		V
			DS3675	0.4	0.5		V
I_{ID}	Logical "1" Drive Current	$V_{CC} = 4.5V, V_{OUT} = 0V, (Note 4)$		-250		mA	
I_{OD}	Logical "0" Drive Current	$V_{CC} = 4.5V, V_{OUT} = 4.5V, (Note 4)$		150		mA	
I_{HZ}	TRI-STATE Output Current	$V_{OUT} = 0.4V$ to $2.4V, Output Disable = 2.0V$		-40	40	μA	
I_{CC}	Power Supply Current	$V_{CC} = 5.5V$	Output Disable = 3V All Other Inputs = 0V		60	100	mA
			Input Enable = 3V All Other Inputs = 0V		40	80	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS1645 and DS1675 and across the 0°C to +70°C range for the DS3645 and DS3675. All typical values are for $T_A = 25^\circ C$ and $V_{CC} = 5V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

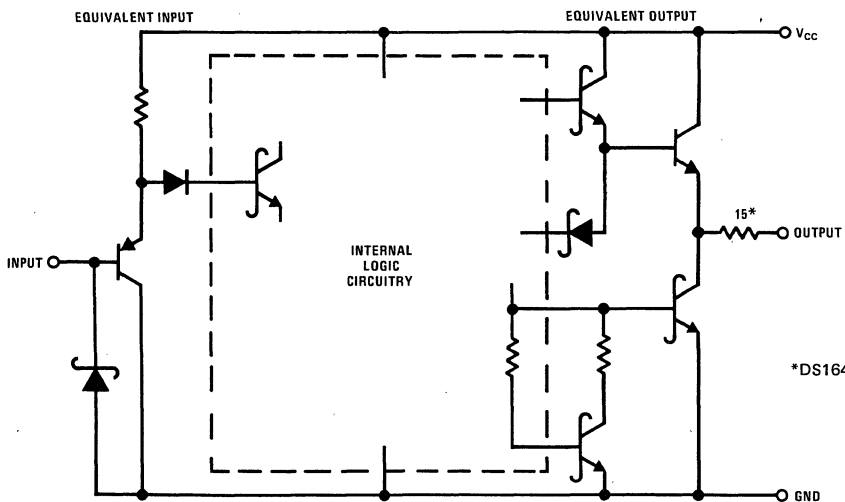
Note 4: When measuring output drive current and switching response for the DS1675 and DS3675 a 15 ohm resistor should be placed in series with each output. This resistor is internal to the DS1645/DS3645, and need not be added.

Switching Characteristics

$V_{CC} = 5V$, $T_A = 25^\circ C$, unless otherwise noted. (Note 4)

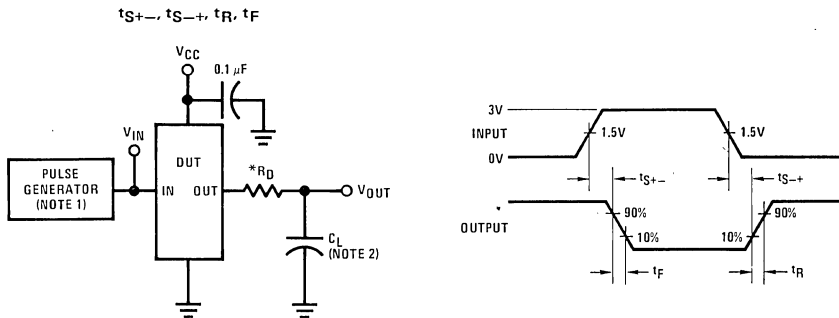
PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
tS ₋	Storage Delay Negative Edge	(Figure 1) $C_L = 50\text{ pF}$		4.5	7	ns
		$C_L = 500\text{ pF}$		8	12	ns
tS ₊	Storage Delay Positive Edge	(Figure 1) $C_L = 50\text{ pF}$		6	8	ns
		$C_L = 500\text{ pF}$		9	13	ns
tF	Fall Time	(Figure 1) $C_L = 50\text{ pF}$		5	8	ns
		$C_L = 500\text{ pF}$		21	35	ns
tR	Rise Time	(Figure 1) $C_L = 50\text{ pF}$		6	9	ns
		$C_L = 500\text{ pF}$		22	35	ns
tSET-UP	Set-Up Time on Data Input Before Input Enables Goes Low		10	0		ns
tHOLD	Hold Time on Data Input After Input Enable Goes Low		15	5		ns
tW	Minimum Width of Enable Pulse to Latch Data		20	5		ns
tZL	Delay from Disable Input to Logical "0" Level (from High Impedance State)	$C_L = 50\text{ pF}$, $R_L = 2\text{ k}\Omega$ to V_{CC} , (Figure 2)		10	15	ns
tZH	Delay from Disable Input to Logical "1" Level (from High Impedance State)	$C_L = 50\text{ pF}$, $R_L = 2\text{ k}\Omega$ to Ground, (Figure 2)		10	15	ns
tLZ	Delay from Disable Input to High Impedance State (from Logical "0" Level)	$C_L = 50\text{ pF}$, $R_L = 400\Omega$ to V_{CC} , (Figure 3)		16	25	ns
tHZ	Delay from Disable Input to High Impedance State (from Logical "1" Level)	$C_L = 50\text{ pF}$, $R_L = 400\Omega$ to Ground, (Figure 3)		16	25	ns

Schematic Diagram



*DS1645/DS3645 only

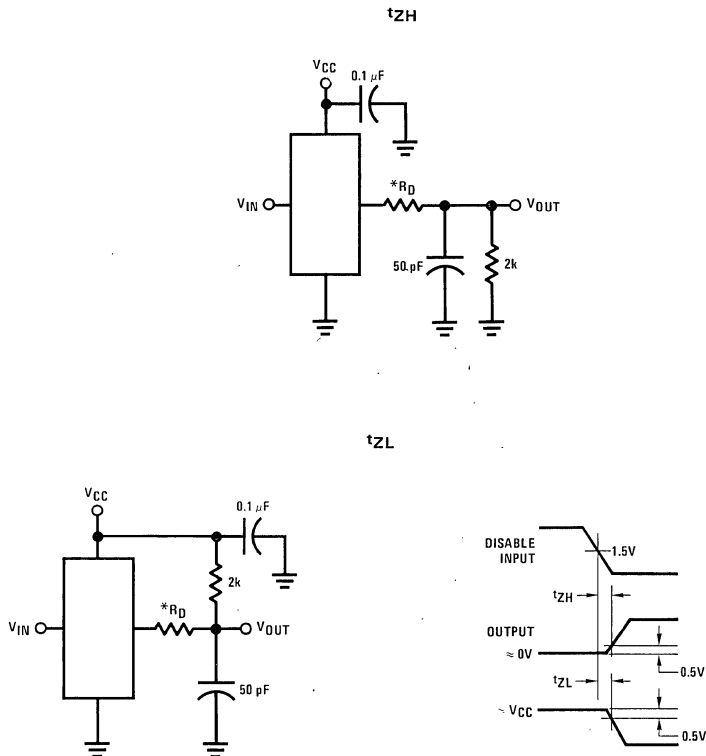
AC Test Circuits and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: Z_{OUT} = 50 Ω and PRR ≤ 1 MHz. Rise and fall times between 10% and 90% points ≤ 5 ns.

Note 2: C_L includes probe and jig capacitance.

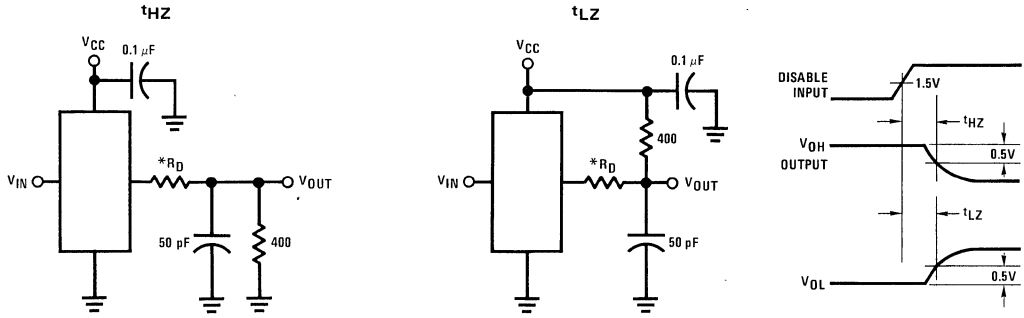
FIGURE 1



*Internal on DS1645 and DS3645

FIGURE 2

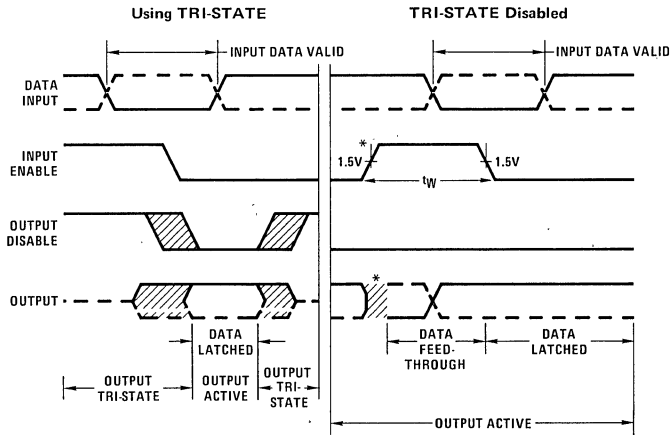
AC Test Circuits and Switching Time Waveforms (Continued)



* Internal on DS1645 and DS3645

FIGURE 3

Operating Waveforms

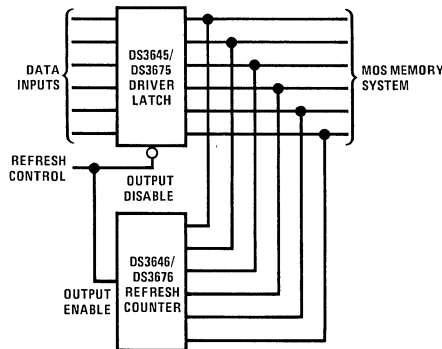


* When the Input Enable makes a positive transition the output will be indeterminate for a short duration. The positive transition of the Input Enable normally occurs during a don't-care timing state at the output.

Typical Applications

The DS3645 and DS3675 latch/driver has TRI-STATE outputs, which allows the outputs to be tied with those of another TRI-STATE driver, such as the DS3646 and

DS3676 refresh counter. The DS3645 and DS3675 can be disabled while the alternate driver controls the address lines into the memory system.



DS1647/DS3647, DS1677/DS3677, DS16147/DS36147, DS16177/DS36177 Quad TRI-STATE® MOS Memory I/O Registers

General Description

The DS1647/DS3647 series are 4-bit I/O buffer registers intended for use in MOS memory systems. The circuits employ a fall-through latch for data storage. This method of latching captures the data in parallel with the output, thus eliminating the delays encountered in other designs. The circuits use Schottky-clamped transistor logic for minimum propagation delay and employ PNP input transistors so that input currents are low, allowing large fan-out to these circuits needed in a memory system.

Two pins per bit are provided, and data transfer is bi-directional so that the register can handle both input and output data. The direction of data flow is controlled through the input enables. The latch control, when taken low, will cause the register to hold the data present at that time and display it at the outputs. Data can be latched into the register independent of the output disables or EXPANSION input. Either or both of the outputs may be taken to the high-impedance state with the output disables. The EXPANSION pin disables both outputs to facilitate multiplexing with other I/O registers on the same data lines.

The "B" port outputs in the DS16147/DS36147 and DS16177/DS36177 are open collectors, and in the

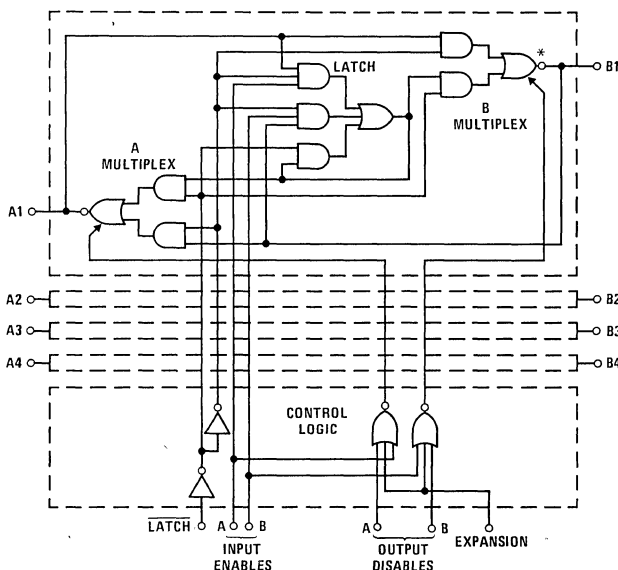
DS1647/DS3647 and DS1677/DS3677 they are TRI-STATE. The "B" port outputs are also designed for use in bus organized data transmission systems and can sink 80 mA and source -5.2 mA. The "A" port outputs in all four types are TRI-STATE.

Data going from port "A" to port "B" is inverted in the DS1647/DS3647 and DS16147/DS36147 and is not inverted in the DS1677/DS3677 and DS16177/DS36177. Data going from port "B" to port "A" is inverted in all four types.

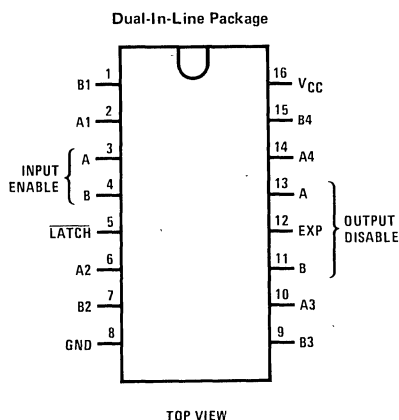
Features

- PNP inputs minimize loading
- Fall-through latch design
- Propagation delay of only 15 ns
- TRI-STATE outputs
- EXPANSION control
- Bi-directional data flow
- TTL compatible
- Transmission line driver output

Logic and Connection Diagrams



*Inverting DS1647/DS3647 and DS16147/DS36147 only



Order Number DS1647D, DS3647D, DS1677D,
DS3677D, DS16147D, DS36147D, DS16177D,
DS36177D, DS3647N, DS3677N, DS36147N
or DS36177N
See NS Package D16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	-1.5V to +7V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	4.5	5.5	V
Temperature (T _A)			
DS1647, DS1677, DS16147, DS16177	-55	+125	°C
DS3647, DS3677, DS36147, DS36177	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V _{IN(1)} Logic "1" Input Voltage		2.0			V
V _{IN(0)} Logic "0" Input Voltage				0.8	V
I _{IN(1)} Logic "1" Input Current	V _{CC} = 5.5V, V _{IN} = 5.5V	Latch, Disable Inputs	0.1	40	μA
		Expansion	0.2	80	μA
		A Ports, B Ports	0.2	100	μA
		Enable Inputs	0.4	200	μA
I _{IN(0)} Logic "0" Input Current	V _{CC} = 5.5V, V _{IN} = 0.5V	Latch, Disable Inputs	-25	-250	μA
		Expansion	-50	-500	μA
		A Ports, B Ports	-50	-500	μA
		Enable, Inputs	-0.1	-1.25	mA
V _{CLAMP} Input Clamp Voltage	V _{CC} = 4.5V, I _{IN} = -18 mA		-0.6	-1.2	V
V _{OL(A)} Logic "0" Output Voltage A Ports	V _{CC} = 4.5V, I _{OL} = 20 mA		0.4	0.5	V
V _{OL(B)} Logic "0" Output Voltage B Ports	V _{CC} = 4.5V	I _{OL} = 30 mA	0.3	0.4	V
		I _{OL} = 50 mA	0.4	0.5	V
V _{OH(A)} Logic "1" Output Voltage A Ports	I _{OH} = -1 mA	V _{CC} = 5V	3.0	3.4	V
		V _{CC} = 4.5V	2.5	3.4	V
V _{OH(B)} Logic "1" Output Voltage B Ports	I _{OH} = -5.2 mA, (Note 4)	V _{CC} = 5V	2.9	3.3	V
		V _{CC} = 4.5V	2.4	3.3	V
I _{OS(A)} Output Short-Circuit Current A Port	V _{CC} = 4.5V to 5.5V, V _{OUT} = 0V, (Note 5)	-30	-50	-100	mA
I _{OS(B)} Output Short-Circuit Current B Port	V _{CC} = 4.5V to 5.5V, V _{OUT} = 0V, (Notes 4 and 5)	-30	-60	-100	mA
I _{CC} Power Supply Current	Exp = 3V, A Ports = 0V, B Ports Open, All Other Pins = 0V	DS1647, DS16147	100	110	mA
		DS3647, DS36147	100	140	mA
	Enable A, Latch = 3V, A Ports = 0V, B Ports Open, All Other Pins = 0V	DS1647, DS16147	70	80	mA
		DS3647, DS36147	70	105	mA
	Exp = 3V, A Ports = 0V, B Ports Open, All Other Pins = 0V	DS1677, DS16177	105	115	mA
		DS3677, DS36177	105	145	mA
	Enable A, Latch, A Ports = 3V, B Ports Open, All Other Pins = 0V	DS1677, DS16177	75	85	mA
		DS3677, DS36177	75	110	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS1647, DS1677, DS16147, DS16177 and across the 0°C to +70°C range for the DS3647, DS3677, DS36147, DS36177. All typicals are given for V_{CC} = 5V and T_A = 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted.

Note 4: Not applicable to DS16147/DS36147 or DS16177/DS36177.

Note 5: Only one output at a time should be shorted.



Switching Characteristics (V_{CC} = 5V, T_A = 25°C)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
DATA TRANSFER B PORT TO A PORT, ALL DEVICES						
t _{pd0}	Propagation Delay to a Logic "0"	C _L = 50 pF, R _L = 280 Ω, (Figures 1 and 4)		7.5	15	ns
t _{pd1}	Propagation Delay to a Logic "1"	C _L = 50 pF, R _L = 280 Ω, (Figures 1 and 4)		6.0	12	ns
A PORT CONTROL FROM OUTPUT DISABLE A INPUT, ALL DEVICES						
t _{LZ}	Delay to High Impedance from Logic "0"	(Figures 1 and 5)		13	20	ns
t _{HZ}	Delay to High Impedance from Logic "1"	(Figures 1 and 6)		14	20	ns
t _{ZL}	Delay to Logic "0" from High Impedance	(Figures 1 and 7)		10	15	ns
t _{ZH}	Delay to Logic "1" from High Impedance	(Figures 1 and 8)		25	35	ns
DATA TRANSFER A PORT TO B PORT, DS1647/DS3647						
t _{pd0}	Propagation Delay to a Logic "0"	C _L = 50 pF, R _L = 100 Ω, (Figures 2 and 4)		6.5	12	ns
t _{pd1}	Propagation Delay to a Logic "1"	C _L = 50 pF, R _L = 100 Ω, (Figures 2 and 4)		8.0	15	ns
DATA TRANSFER A PORT TO B PORT, DS1677/DS3677						
t _{pd0}	Propagation Delay to a Logic "0"	C _L = 50 pF, R _L = 100 Ω, (Figures 2 and 4)		12.5	20	ns
t _{pd1}	Propagation Delay to a Logic "1"	C _L = 50 pF, R _L = 100 Ω, (Figures 2 and 4)		8.5	15	ns
DATA TRANSFER A PORT TO B PORT DS16147/DS36147						
t _{pd0}	Propagation Delay to a Logic "0"	C _L = 50 pF, (Figures 3 and 4)		18	25	ns
t _{pd1}	Propagation Delay to a Logic "1"	C _L = 50 pF, (Figures 3 and 4)		7.0	15	ns
DATA TRANSFER A PORT TO B PORT, DS16177/DS36177						
t _{pd0}	Propagation Delay to a Logic "0"	C _L = 50 pF, (Figures 3 and 4)		13.5	21	ns
t _{pd1}	Propagation Delay to a Logic "1"	C _L = 50 pF, (Figures 3 and 4)		18	25	ns
B PORT CONTROL FROM OUTPUT DISABLE B INPUT, DS1647/DS3647, DS1677/DS3677						
t _{LZ}	Delay to High Impedance from Logic "0"	(Figures 2 and 5)		15	25	ns
t _{HZ}	Delay to High Impedance from Logic "1"	(Figures 2 and 6)		14	20	ns
t _{ZL}	Delay to Logic "0" from High Impedance	(Figures 2 and 7)		10	16	ns
t _{ZH}	Delay to Logic "1" from High Impedance	(Figures 2 and 8)		25	35	ns
B PORT CONTROL FROM OUTPUT DISABLE B INPUT, DS16147/DS36147, DS16177/DS36177						
t _{LZ}	Delay to High Impedance from Logic "0"	(Figures 3 and 5)		15	25	ns
t _{ZL}	Delay to Logic "0" from High Impedance	(Figures 3 and 7)		11	17	ns
LATCH SET-UP AND HOLD TIMES, ALL DEVICES						
t _{SET-UP}	Set-Up Time of Data Input Before Latch Goes Low		10	0		ns
t _{HOLD}	Hold Time of Data Input After Latch Goes Low		0			ns

Product Description

DEVICE NUMBER	B PORT TO A PORT FUNCTION	A PORT TO B PORT FUNCTION	A PORT OUTPUTS	B PORT OUTPUTS
DS1647/DS3647	Inverting	Inverting	TRI-STATE	TRI-STATE
DS1677/DS3677	Inverting	Non-Inverting	TRI-STATE	TRI-STATE
DS16147/DS36147	Inverting	Inverting	TRI-STATE	Open-Collector
DS16177/DS36177	Inverting	Non-Inverting	TRI-STATE	Open-Collector

Truth Table

INPUT ENABLES		LATCH	OUTPUT DISABLES		EXPANSION	A PORTS A1-A4 ALL DEVICES	B PORTS B1-B4 DS1647, DS16147 DS3647, DS36147	B PORTS B1-B4 DS1677, DS16177 DS3677, DS36177	COMMENTS
A	B		A	B					
1	0	1	0	0	0	Hi-Z	\bar{A}	A	Data In on A, output to B
0	1	1	0	0	0	\bar{B}	Hi-Z	Hi-Z	Data In on B, output to A
1	0	0	0	0	0	Hi-Z	\bar{A}	A	Data stored which is present when latch goes low
0	1	0	0	0	0	\bar{B}	Hi-Z	Hi-Z	Data stored which is present when latch goes low
1	0	X	0	1	0	Hi-Z	Hi-Z	Hi-Z	Both A and B in Hi-Z state, Data In on A, may be latched
0	1	X	1	0	0	Hi-Z	Hi-Z	Hi-Z	Both A and B in Hi-Z state, Data In on B, may be latched
X	X	X	X	X	1	Hi-Z	Hi-Z	Hi-Z	Both A and B in Hi-Z state

AC Test Circuits

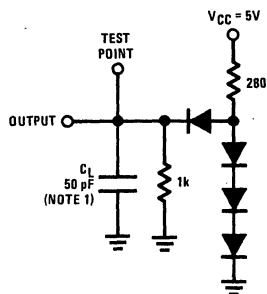


FIGURE 1. A Port Load, All Circuits

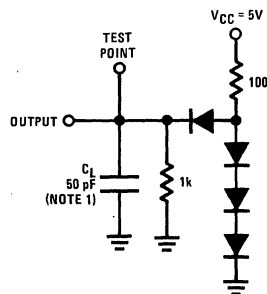


FIGURE 2. B Port Load, DS3647, DS3677

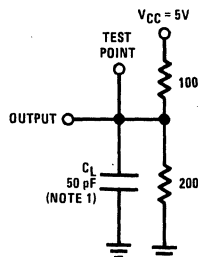
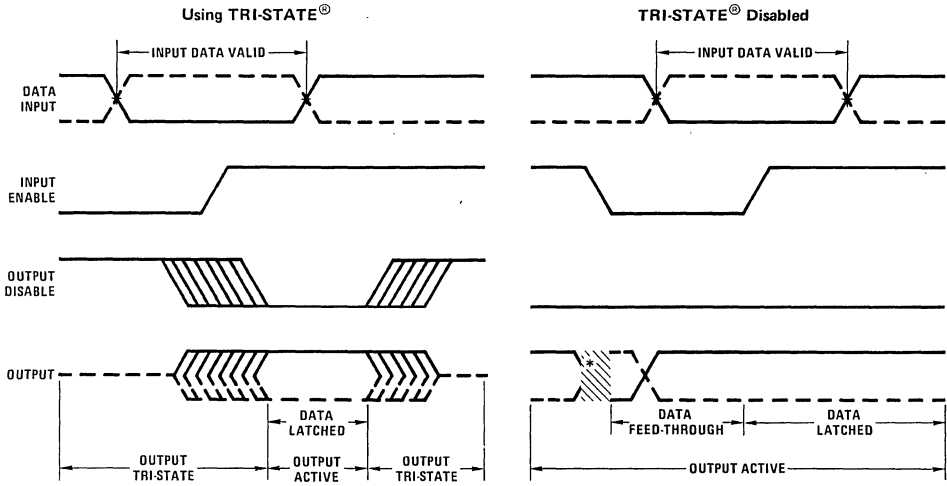


FIGURE 3. B Port Load, DS36147, DS36177

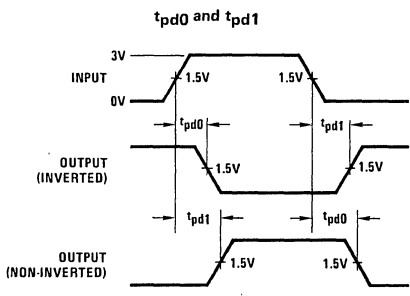
Note 1: C_L includes probe and jig capacitance.

Operating Waveforms



*When the Input Enable makes a negative transition, the output will be indeterminate for a short duration. The negative transition of the Input Enable normally occurs during a don't-care timing state at the output.

Switching Time Waveforms



Input Characteristics: $f = 1 \text{ MHz}$, $t_R = t_F \leq 5 \text{ ns}$ (10% to 90% points), duty cycle = 50%, $Z_{OUT} = 50 \Omega$

FIGURE 4

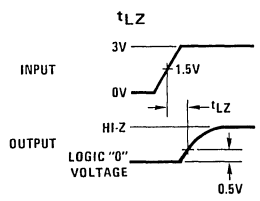


FIGURE 5

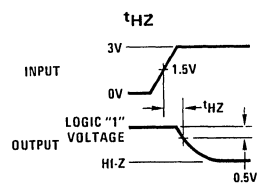


FIGURE 6

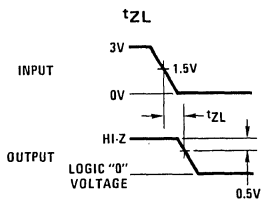


FIGURE 7

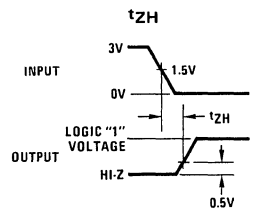
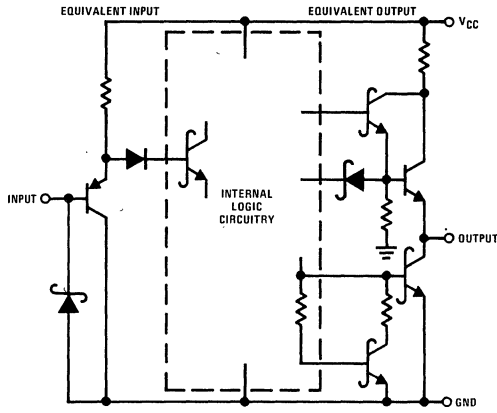


FIGURE 8

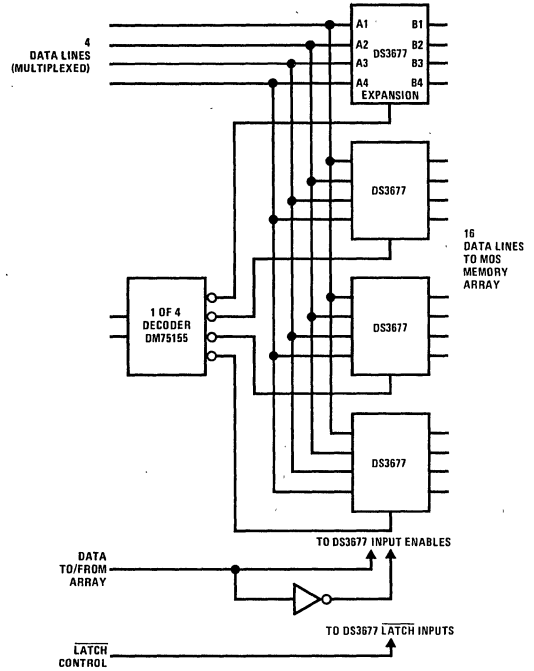
Schematic Diagram



Note. Data pins A1–A4 and B1–B4 consist of an input and an output tied together.

Typical Application

The diagram below shows how the DS3677 can be used as a register capable of multiplexing data lines.



DS1648/DS3648, DS1678/DS3678 TRI-STATE® TTL to MOS Multiplexers/Drivers

General Description

The DS1648/DS3648 and DS1678/DS3678 are quad 2-input multiplexers with TRI-STATE outputs designed to drive the large capacitive loads (up to 500 pF) associated with MOS memory systems. A PNP input structure is employed to minimize input currents so that driver loading in large memory systems is reduced. The circuit employs Schottky-clamped transistors for high speed and TRI-STATE outputs for bus operation.

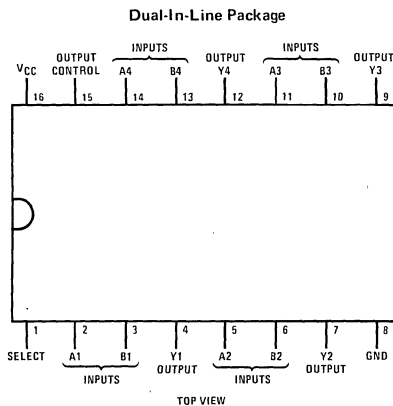
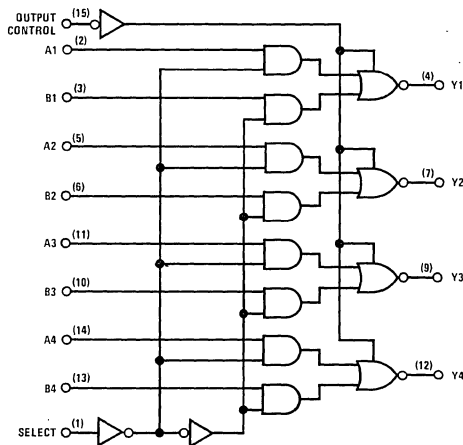
The DS1648/DS3648 has a 15 Ω resistor in series with the outputs to dampen transients caused by the fast-switching output. The DS1678/DS3678 has a direct,

low impedance output for use with or without an external resistor.

Features

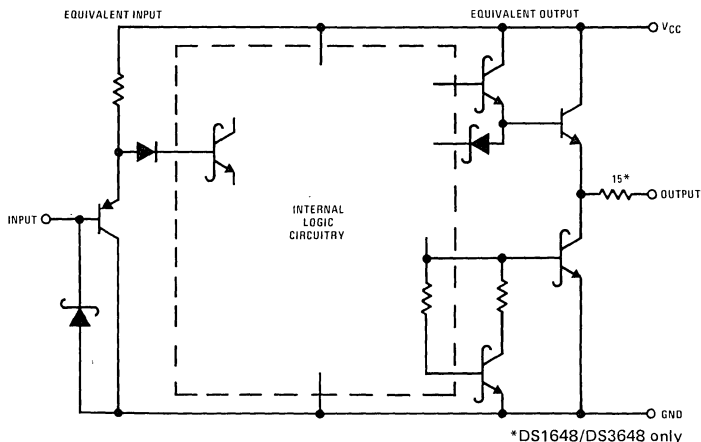
- TRI-STATE outputs interface directly with system bus
- Schottky-clamped for better ac performance
- PNP inputs to minimize input loading
- TTL compatible
- High-speed capacitive load drivers
- Built-in damping resistor (DS1648/DS3648 only)

Logic and Connection Diagrams



Order Number DS1648J, DS3648J, DS1678J,
DS3678J, DS3648N or DS3678N
See NS Package J16A or N16A

Schematic Diagram



Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Logical "1" Input Voltage	7V
Logical "0" Input Voltage	-1.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation * at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	4.5	5.5	V
Temperature (T _A)			
DS1648, DS1678	-55	+125	°C
DS3648, DS3678	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IN(1)}	Logical "1" Input Voltage	2.0			V	
V _{IN(0)}	Logical "0" Input Voltage			0.8	V	
I _{IN(1)}	Logical "1" Input Current V _{CC} = 5.5V, V _{IN} = 5.5V		0.1	40	μA	
I _{IN(0)}	Logical "0" Input Current V _{CC} = 5.5V, V _{IN} = 0.5V		-50	-250	μA	
V _{CLAMP}	Input Clamp Voltage V _{CC} = 4.5V, I _{IN} = -18 mA		-0.75	-1.2	V	
V _{OH}	Logical "1" Output Voltage (No Load) V _{CC} = 4.5V, I _{OH} = -10 μA	DS1648/DS1678	2.7	3.6	V	
		DS3648/DS3678	2.8	3.6	V	
V _{OL}	Logical "0" Output Voltage (No Load) V _{CC} = 4.5V, I _{OL} = 10 μA	DS1648/DS1678		0.25	0.4	V
		DS3648/DS3678		0.25	0.35	V
V _{OH}	Logical "1" Output Voltage (With Load) V _{CC} = 4.5V, I _{OH} = -1.0 mA	DS1648	2.4	3.5	V	
		DS1678	2.5	3.5	V	
		DS3648	2.6	3.5	V	
		DS3678	2.7	3.5	V	
V _{OL}	Logical "0" Output Voltage (With Load) V _{CC} = 4.5V, I _{OL} = 20 mA	DS1648		0.6	1.1	V
		DS1678		0.4	0.5	V
		DS3648		0.6	1.0	V
		DS3678		0.4	0.5	V
I _{1D}	Logical "1" Drive Current V _{CC} = 4.5V, V _{OUT} = 0V, (Note 4)		-250		mA	
I _{0D}	Logical "0" Drive Current V _{CC} = 4.5V, V _{OUT} = 4.5V, (Note 4)		150		mA	
I _{Hi-Z}	TRI-STATE Output Current V _{OUT} = 0.4V to 2.4V, Output Control = 2.0V	-40		40	μA	
I _{CC}	Power Supply Current V _{CC} = 5.5V	Output Control = 3V All Other Inputs at 0V		42	60	mA
		All Inputs at 0V		20	32	mA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS1648 and DS1678 and across the 0°C to +70°C range for the DS3648 and DS3678. All typical values are for T_A = 25°C and V_{CC} = 5V.

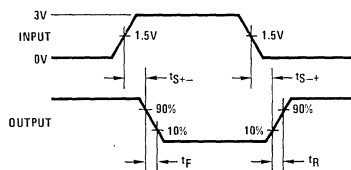
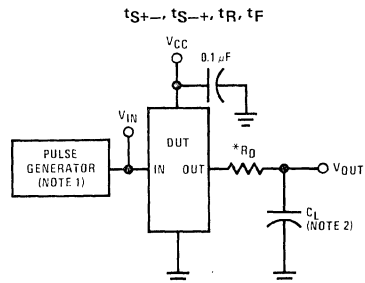
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: When measuring output drive current and switching response for the DS1678 and DS3678 a 15 Ω resistor should be placed in series with each output. This resistor is internal to the DS1648/DS3648 and need not be added.

Switching Characteristics (V_{CC} = 5V, T_A = 25°C) (Note 4)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
t _{S+} -	Storage Delay Negative Edge	(Figure 1) C _L = 50 pF		5	7	ns
		C _L = 500 pF		9	12	ns
t _{S-} +	Storage Delay Positive Edge	(Figure 1) C _L = 50 pF		6	8	ns
		C _L = 500 pF		9	13	ns
t _F	Fall Time	(Figure 1) C _L = 50 pF		5	8	ns
		C _L = 500 pF		22	35	ns
t _R	Rise Time	(Figure 1) C _L = 50 pF		6	9	ns
		C _L = 500 pF		22	35	ns
t _{ZL}	Delay from Output Control Input to Logical "0" Level (from High Impedance State)	C _L = 50 pF, R _L = 2 kΩ to V _{CC} , (Figure 2)		10	15	ns
t _{ZH}	Delay from Output Control Input to Logical "1" Level (from High Impedance State)	C _L = 50 pF, R _L = 2 kΩ to Gnd, (Figure 2)		8	15	ns
t _{LZ}	Delay from Output Control Input to High Impedance State (from Logical "0" Level)	C _L = 50 pF, R _L = 400 Ω to V _{CC} , (Figure 3)		15	25	ns
t _{HZ}	Delay from Output Control Input to High Impedance State (from Logical "1" Level)	C _L = 50 pF, R _L = 400 Ω to Gnd, (Figure 3)		10	25	ns
t _{S+} -	Propagation Delay to Logical "0" Transition When Select Selects A	C _L = 50 pF, (Figure 1)		12	15	ns
t _{S-} +	Propagation Delay to Logical "1" Transition When Select Selects A	C _L = 50 pF, (Figure 1)		14	17	ns
t _{S+} -	Propagation Delay to Logical "0" Transition When Select Selects B	C _L = 50 pF, (Figure 1)		16	20	ns
t _{S-} +	Propagation Delay to Logical "1" Transition When Select Selects B	C _L = 50 pF, (Figure 1)		14	20	ns

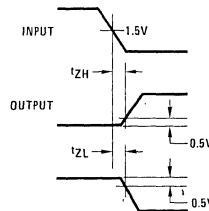
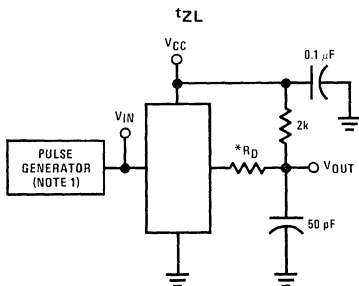
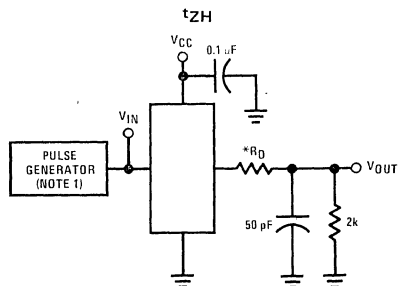
AC Test Circuits and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: Z_O = 50 Ω and PRR ≤ 1 MHz. Rise and fall times between 10% and 90% points ≤ 5 ns.

Note 2: C_L includes probe and jig capacitance.

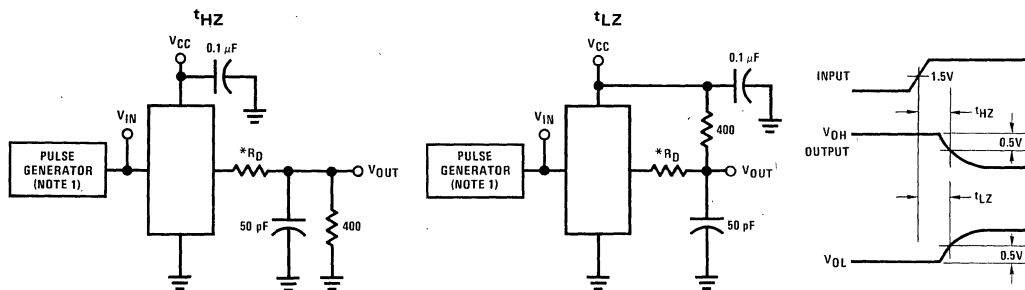
FIGURE 1



*Internal on DS1648 and DS3648

FIGURE 2

AC Test Circuits and Switching Time Waveforms (Continued)



*Internal on DS1648 and DS3648

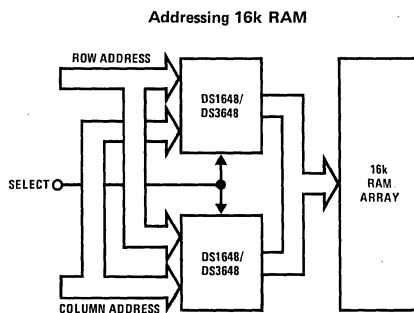
FIGURE 3

Truth Table

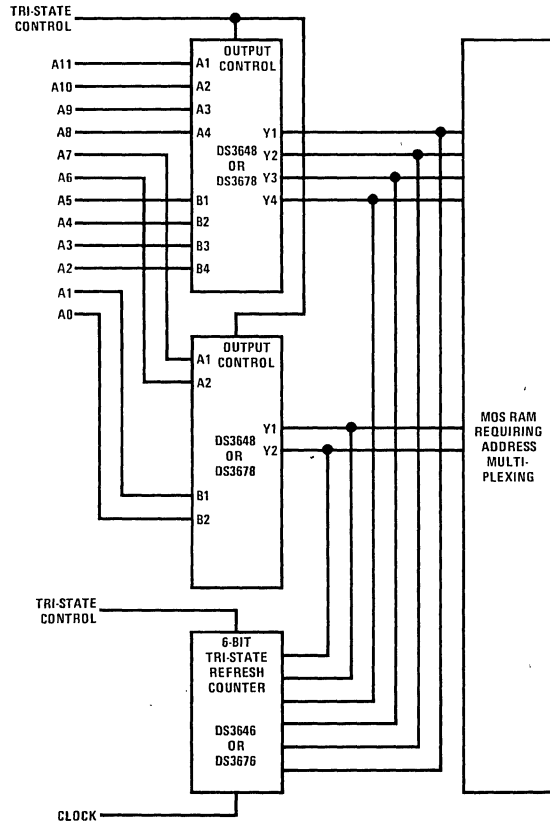
OUTPUT CONTROL	INPUTS			OUTPUTS
	SELECT	A	B	
H	X	X	X	Hi-Z
L	L	L	X	H
L	L	H	X	L
L	H	X	L	H
L	H	X	H	L

H = High level
 L = Low level
 X = Don't care
 Hi-Z = TRI-STATE mode

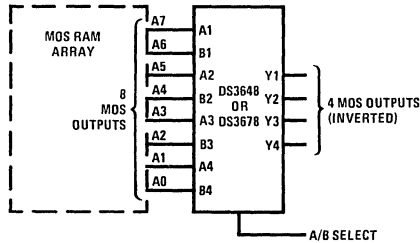
Typical Applications



Refreshing Using TRI-STATE Counter



2:1 Multiplexing of RAM Outputs



DS1649/DS3649, DS1679/DS3679 Hex TRI-STATE® TTL to MOS Drivers

General Description

The DS1649/DS3649 and DS1679/DS3679 are Hex TRI-STATE MOS drivers with outputs designed to drive large capacitive loads up to 500 pF associated with MOS memory systems. PNP input transistors are employed to reduce input currents allowing the large fan-out to these drivers needed in memory systems. The circuit has Schottky-clamped transistor logic for minimum propagation delay, and TRI-STATE outputs for bus operation.

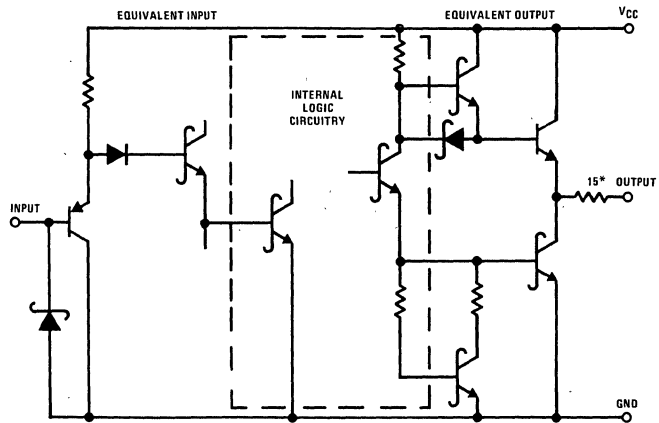
The DS1649/DS3649 has a 15 Ω resistor in series with the outputs to dampen transients caused by the fast-switching output. The DS1679/DS3679 has a direct low

impedance output for use with or without an external resistor.

Features

- High speed capabilities
 - Typ 9 ns driving 50 pF
 - Typ 30 ns driving 500 pF
- TRI-STATE outputs for data bussing
- Built-in 15 Ω damping resistor (DS1649/DS3649)
- Same pin-out as DM8096 and DM74366

Schematic Diagram



*DS1649/DS3649 only

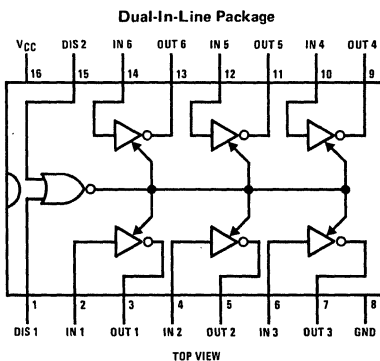
Truth Table

DISABLE INPUT		INPUT	OUTPUT
DIS 1	DIS 2		
0	0	0	1
0	0	1	0
0	1	X	Hi-Z
1	0	X	Hi-Z
1	1	X	Hi-Z

X = Don't care

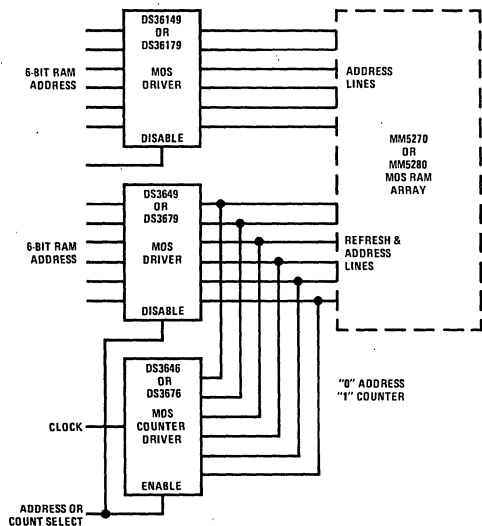
Hi-Z = TRI-STATE mode

Connection Diagram



Order Number DS1649J, DS3649J,
DS1679J, DS3679J, DS3649N or DS3679N
See NS Package J16A or N16A

Typical Application



Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Logical "1" Input Voltage	7.0V
Logical "0" Input Voltage	-1.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1371 mW
Molded Package	1280 mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	4.5	5.5	V
Temperature (T _A)			
DS1649, DS1679	-55	+125	°C
DS3649, DS3679	0	+70	°C

*Derate cavity package 9.1 mW/°C above 25°C; derate molded package 10.2 mW/°C above 25°C.

Electrical Characteristics (Note 2 and 3)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS	
V _{IN(1)}	Logical "1" Input Voltage			2.0			V	
V _{IN(0)}	Logical "0" Input Voltage					0.8	V	
I _{IN(1)}	Logical "1" Input Current	V _{CC} = 5.5V	V _{IN} = 5.5V		0.1	40	μA	
I _{IN(0)}	Logical "0" Input Current	V _{CC} = 5.5V	V _{IN} = 0.5V		-50	-250	μA	
V _{CLAMP}	Input Clamp Voltage	V _{CC} = 4.5V	I _{IN} = -18 mA		-0.75	-1.2	V	
V _{OH}	Logical "1" Output Voltage (No Load)	V _{CC} = 4.5V	I _{OH} = -10 μA	DS1649/DS1679	2.7	3.6	V	
				DS3649/DS3679	2.8	3.6	V	
V _{OL}	Logical "0" Output Voltage (No Load)	V _{CC} = 4.5V	I _{OL} = 10 μA	DS1649/DS1679		0.25	0.4	V
				DS3649/DS3679		0.25	0.35	V
V _{OH}	Logical "1" Output Voltage (With Load)	V _{CC} = 4.5V	I _{OH} = -1.0 mA	DS1649	2.4	3.5	V	
				DS1679	2.5	3.5	V	
				DS3649	2.6	3.5	V	
				DS3679	2.7	3.5	V	
V _{OL}	Logical "0" Output Voltage (With Load)	V _{CC} = 4.5V	I _{OL} = 20 mA	DS1649		0.6	1.1	V
				DS1679		0.4	0.5	V
				DS3649		0.6	1.0	V
				DS3679		0.4	0.5	V
I _{ID}	Logical "1" Drive Current	V _{CC} = 4.5V	V _{OUT} = 0V (Note 4)		-250		mA	
I _{OD}	Logical "0" Drive Current	V _{CC} = 4.5V	V _{OUT} = 4.5V (Note 4)		150		mA	
Hi-Z	TRI-STATE Output Current	V _{OUT} = 0.4V to 2.4V	DIS1 or DIS2 = 2.0V	-40		40	μA	
I _{CC}	Power Supply Current	V _{CC} = 5.5V	One DIS Input = 3.0V All Other Inputs = X		42	75	mA	
			All Inputs = 0V		11	20	mA	

Switching Characteristics (V_{CC} = 5V, T_A = 25°C) (Note 4)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
t _{S+}	Storage Delay Negative Edge	(Figure 1)	C _L = 50 pF		4.5	7	ns
			C _L = 500 pF		7.5	12	ns
t _{S-}	Storage Delay Position Edge	(Figure 1)	C _L = 50 pF		5	8	ns
			C _L = 500 pF		8	13	ns
t _F	Fall Time	(Figure 1)	C _L = 50 pF		5	8	ns
			C _L = 500 pF		22	35	ns
t _R	Rise Time	(Figure 1)	C _L = 50 pF		6	9	ns
			C _L = 500 pF		21	35	ns
t _{ZL}	Delay from Disable Input to Logical "0" Level (from High Impedance State)	C _L = 50 pF to Gnd	R _L = 2 kΩ to V _{CC} (Figure 2)		10	15	ns
t _{ZH}	Delay from Disable Input to Logical "1" Level (from High Impedance State)	C _L = 50 pF to Gnd	R _L = 2 kΩ to Gnd (Figure 2)		8	15	ns
t _{LZ}	Delay from Disable Input to High Impedance State (from Logical "0" Level)	C _L = 50 pF to Gnd	R _L = 400 Ω to V _{CC} (Figure 3)		15	25	ns
t _{HZ}	Delay from Disable Input to High Impedance State (from Logical "1" Level)	C _L = 50 pF to Gnd	R _L = 400 Ω to Gnd (Figure 3)		10	25	ns

Notes

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to $+125^{\circ}\text{C}$ temperature range for the DS1649 and DS1679 and across the 0°C to $+70^{\circ}\text{C}$ range for the DS3649 and DS3679. All typical values are for $T_A = 25^{\circ}\text{C}$ and $V_{CC} = 5\text{V}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: When measuring output drive current and switching response for the DS1679 and DS3679 a $15\ \Omega$ resistor should be placed in series with each output. This resistor is internal to the DS1649/DS3649 and need not be added.

AC Test Circuits and Switching Time Waveforms

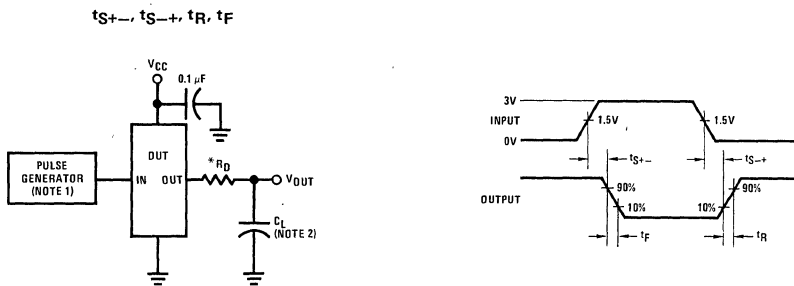


FIGURE 1

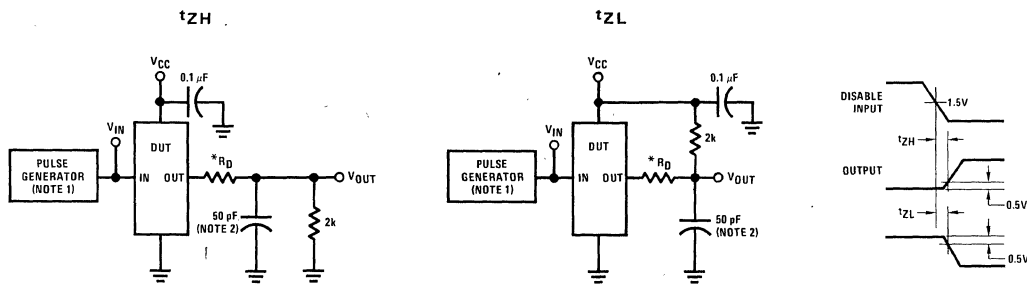


FIGURE 2

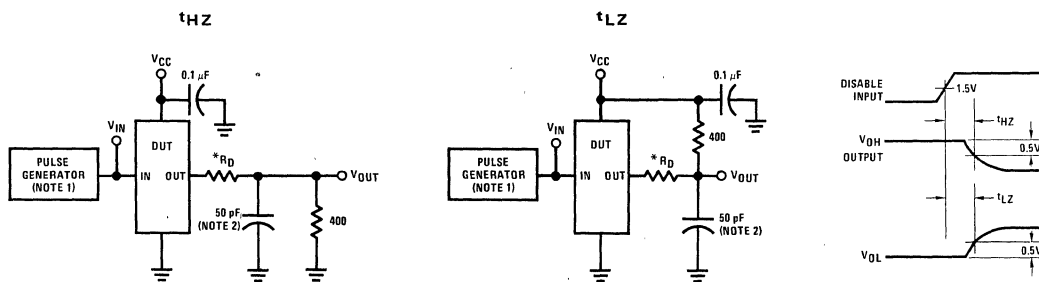


FIGURE 3

*Internal on DS1649 and DS3649

Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\ \Omega$ and $PRR \leq 1\ \text{MHz}$. Rise and fall times between 10% and 90% points $\leq 5\ \text{ns}$.

Note 2: C_L includes probe and jig capacitance.

DS1651/DS3651, DS1653/DS3653 Quad High Speed MOS Sense Amplifiers

General Description

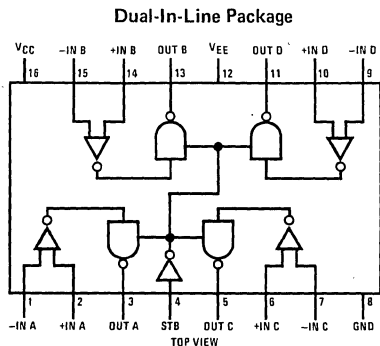
The DS1651/DS3651 and DS1653/DS3653 are TTL compatible high speed circuits intended for sensing in a broad range of MOS memory system applications. Switching speeds have been enhanced over conventional sense amplifiers by application of Schottky technology, and TRI-STATE[®] strobing is incorporated, offering a high impedance output state for bused organization.

The DS1651/DS3651 has active pull-up outputs, and the DS1653/DS3653 offers open collector outputs providing implied "AND" operations.

Features

- High speed
- TTL compatible
- Input sensitivity – ± 7 mV
- TRI-STATE outputs for high speed buses
- Standard supply voltages – ± 5 V
- Pin and function compatible with MC3430 and MC3432

Connection Diagram



Order Number DS1651J, DS1653J, DS3651J,
DS3653J, DS3651N or DS3653N
See NS Package J16A or N16A

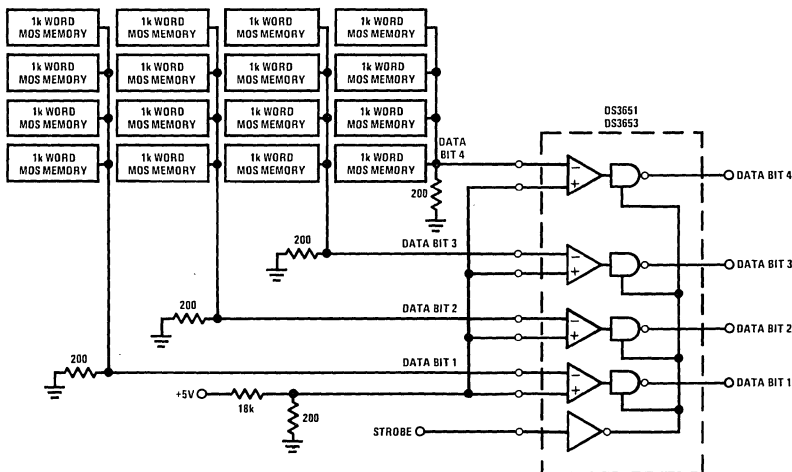
Truth Table

INPUT	STROBE	OUTPUT	
		DS3651	DS3653
$V_{ID} \geq 7$ mV $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$	L	H	Open
	H	Open	Open
-7 mV $\leq V_{ID} \leq +7$ mV $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$	L	X	X
	H	Open	Open
$V_{ID} \leq -7$ mV $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$	L	L	L
	H	Open	Open

L = Low logic state
H = High logic state
Open = TRI-STATE
X = Indeterminate state

Typical Applications

A Typical MOS Memory Sensing Application for a 4k word by 4-bit memory arrangement employing 1103 type memory devices



Note. Only 4 devices are required for a 4k word by 16-bit memory system.

Absolute Maximum Ratings

(Note 1)

Power Supply Voltages	
V _{CC}	+7 V _{DC}
V _{EE}	-7 V _{DC}
Differential-Mode Input Signal Voltage	
Range, V _{IDR}	±6 V _{DC}
Common-Mode Input Voltage Range, V _{ICR}	±5 V _{DC}
Strobe Input Voltage, V _{I(S)}	5.5 V _{DC}
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DS1651, DS1653	4.5	5.5	V _{DC}
DS3651, DS3653	4.75	5.25	V _{DC}
Supply Voltage (V _{EE})			
DS1651, DS1653	-4.5	-5.5	V _{DC}
DS3651, DS3653	-4.75	-5.25	V _{DC}
Operating Temperature (T _A)			
DS1651, DS1653	-55	+125	°C
DS3651, DS3653	0	+70	°C
Output Load Current, (I _{OL})			
		16	mA
Differential-Mode Input			
Voltage Range, V _{IDR}	-5.0	+5.0	V _{DC}
Common-Mode Input			
Voltage Range (V _{ICR})	-3.0	+3.0	V _{DC}
Input Voltage Range (Any Input to GND), (V _{IR})			
	-5.0	+3.0	V _{DC}

Electrical Characteristics

V_{CC} = 5 V_{DC}, V_{EE} = -5 V_{DC}, Min ≤ T_A ≤ Max, unless otherwise noted (Notes 2 and 3)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
V _{IS}	Input Sensitivity, (Note 5) (Common-Mode Voltage Range = -3V ≤ V _{IN} ≤ 3V)	Min ≤ V _{CC} ≤ Max Min ≥ V _{EE} ≥ Max				±7.0	mV
V _{IO}	Input Offset Voltage				2		mV
I _{IB}	Input Bias Current	V _{CC} = Max, V _{EE} = Max				20	μA
I _{IO}	Input Offset Current				0.5		μA
V _{IL(S)}	Strobe Input Voltage (Low State)					0.8	V
V _{IH(S)}	Strobe Input Voltage (High State)			2			V
I _{IL(S)}	Strobe Current (Low State)	V _{CC} = Max, V _{EE} = Max, V _{IN} = 0.4V				-1.6	mA
I _{IH(S)}	Strobe Current (High State)	V _{CC} = Max, V _{EE} = Max	V _{IN} = 2.4V	DS3651, DS3653		40	μA
			V _{IN} = V _{CC}			1	mA
		V _{CC} = Max, V _{EE} = Max	V _{IN} = 2.4V	DS1651, DS1653		100	μA
			V _{IN} = V _{CC}			1	mA
V _{OH}	Output Voltage (High State)	V _{CC} = Min, V _{EE} = Min	I _O = -400 μA	DS1651/DS3651	2.4		V
V _{OL}	Output Voltage (Low State)	V _{CC} = Min, V _{EE} = Min	I _O = 16 mA	DS3651, DS3653		0.45	V
				DS1651, DS1653		0.50	
I _{CEX}	Output Leakage Current	V _{CC} = Min, V _{EE} = Min	V _O = Max	DS1653/DS3653		250	μA
I _{OS}	Output Current Short Circuit	V _{CC} = Max, V _{EE} = Max, (Note 4)		DS1651/DS3651	-18	-70	mA
I _{OFF}	Output Disable Leakage Current	V _{CC} = Max, V _{EE} = Max		DS3651		40	μA
				DS1651		100	μA
I _{CC}	High Logic Level Supply Current	V _{CC} = Max, V _{EE} = Max			45	60	mA
I _{EE}	High Logic Level Supply Current	V _{CC} = Max, V _{EE} = Max			-17	-30	mA

Switching Characteristics

$V_{CC} = 5 V_{DC}$, $V_{EE} = -5 V_{DC}$, $T_A = 25^\circ C$ unless otherwise noted.

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
$t_{PHL(D)}$	High-to-Low Logic Level Propagation Delay Time (Differential Inputs)	5 mV + V_{IS} , (Figure 3)	DS1651/ DS3651	23	45	ns
			DS1653/ DS3653	22	50	ns
$t_{PLH(D)}$	Low-to-High Logic Level Propagation Delay Time (Differential Inputs)	5 mV + V_{IS} , (Figure 3)	DS1651/ DS3651	22	55	ns
			DS1653/ DS3653	24	65	ns
$t_{POH(S)}$	TRI-STATE to High Logic Level Propagation Delay Time (Strobe)	(Figure 1)	DS1651/ DS3651	16	21	ns
$t_{PHO(S)}$	High Logic Level to TRI-STATE Propagation Delay Time (Strobe)	(Figure 1)	DS1651/ DS3651	7	18	ns
$t_{POL(S)}$	TRI-STATE to Low Logic Level Propagation Delay Time (Strobe)	(Figure 1)	DS1651/ DS3651	19	27	ns
$t_{PLO(S)}$	Low Logic Level to TRI-STATE Propagation Delay Time (Strobe)	(Figure 1)	DS1651/ DS3651	14	29	ns
$t_{PHL(S)}$	High-to-Low Logic Level Propagation Delay Time (Strobe)	(Figure 2)	DS1653/ DS3653	16	25	ns
$t_{PLH(S)}$	Low-to-High Logic Level Propagation Delay Time (Strobe)	(Figure 2)	DS1653/ DS3653	13	25	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

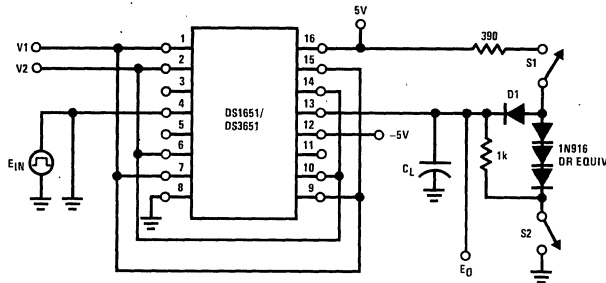
Note 2: Unless otherwise specified min/max limits apply across the $0^\circ C$ to $+70^\circ C$ range for the DS3651, DS3653 and across the $-55^\circ C$ to $+125^\circ C$ range for the DS1651, DS1653. All typical values are for $T_A = 25^\circ C$, $V_{CC} = 5V$ and $V_{EE} = -5V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: A parameter which is of primary concern when designing with sense amplifiers is, what is the minimum differential input voltage required at the sense amplifier input terminals to guarantee a given output logic state. This parameter is commonly referred to as threshold voltage. It is well known that design considerations of threshold voltage are plagued by input offset currents, bias currents, network source resistances, and voltage gain. As a design convenience, the DS1651, DS1653 and DS3651, DS3653 are specified to a parameter called input sensitivity (V_{IS}). This parameter takes into consideration input offset currents and bias currents, and guarantees a minimum input differential voltage to cause a given output logic state with respect to a maximum source impedance of 200Ω at each input.

AC Test Circuits and Switching Time Waveforms



Note. Output of channel B shown under test, other channels are tested similarly.

	V1	V2	S1	S2	CL
tPLO(S)	100 mV	GND	Closed	Closed	15 pF
tPOL(S)	100 mV	GND	Closed	Open	50 pF
tPHO(S)	GND	100 mV	Closed	Closed	15 pF
tPOH(S)	GND	100 mV	Open	Closed	50 pF

CL includes jig and probe capacitance.

EIN waveform characteristics: t_{PLH} and $t_{THL} \leq 10$ ns measured 10% to 90%

PRR = 1 MHz

Duty cycle = 50%

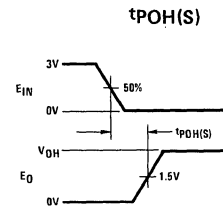
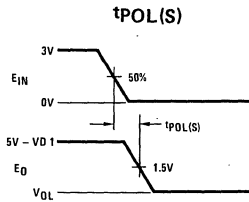
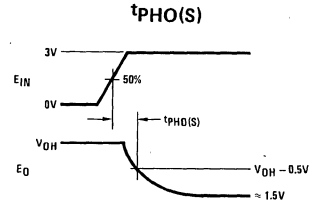
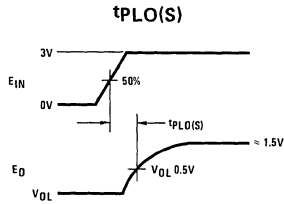
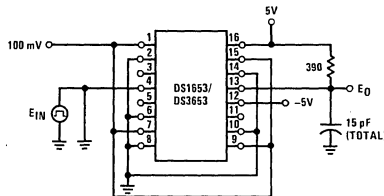
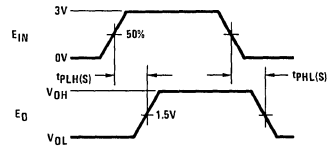


FIGURE 1. Strobe Propagation Delay tPLO(S), tPOL(S), tPHL(S) and tPOH(S)



Note. Output of channel B shown under test, other channels are tested similarly.

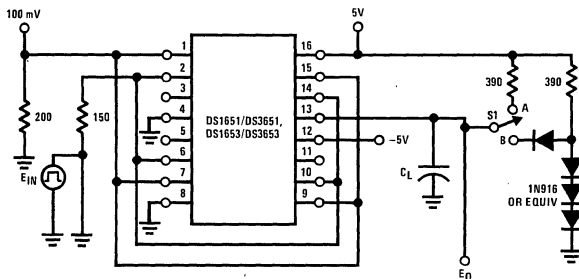


Note. EIN waveform characteristics:

t_{PLH} and $t_{THL} \leq 10$ ns measured 10% to 90%

PRR = 1 MHz, duty cycle = 500 ns

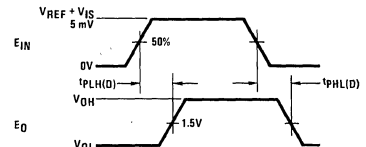
FIGURE 2. Strobe Propagation Delay tPLH(S) and tPHL(S)



Note. Output of channel B shown under test, other channels are tested similarly.

S1 at "A" for DS1653/DS3653, CL = 15 pF total for DS1653/DS3653

S1 at "B" for DS1651/DS3651, CL = 50 pF total for DS1651/DS3651



EIN waveform characteristics:

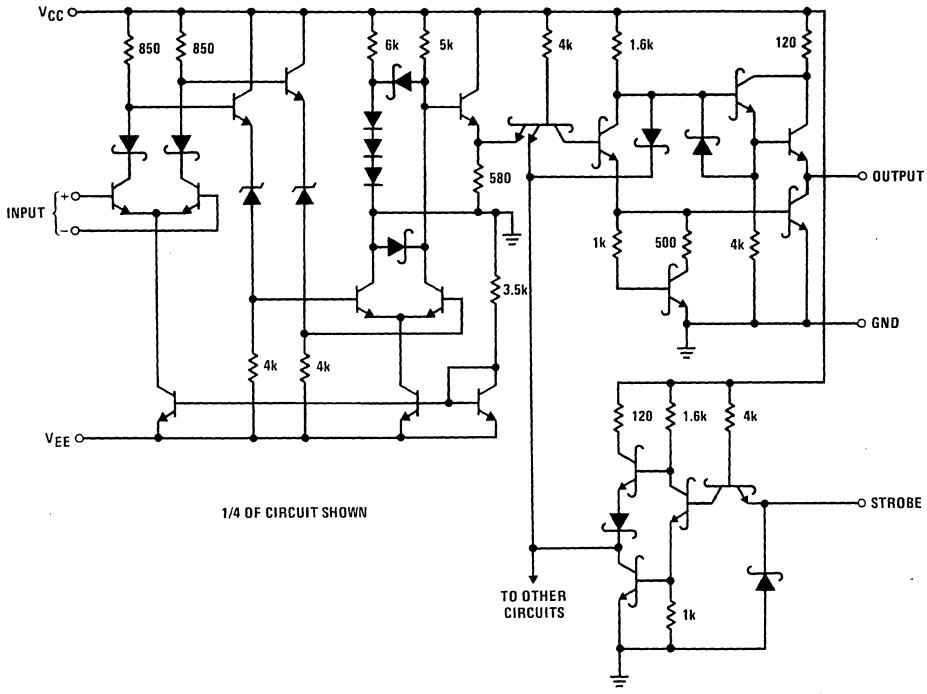
t_{PLH} and $t_{THL} \leq 10$ ns measured 10% to 90%

PRR = 1 MHz, duty cycle = 500 ns

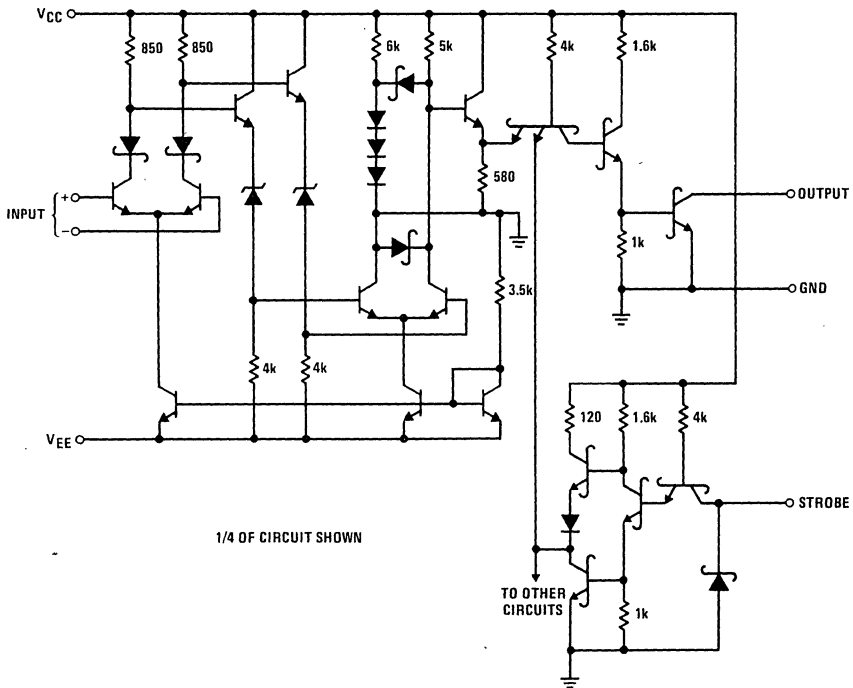
FIGURE 3. Differential Input Propagation Delay tPLH(D) and tPHL(D)

Schematic Diagrams

DS1651/DS3651

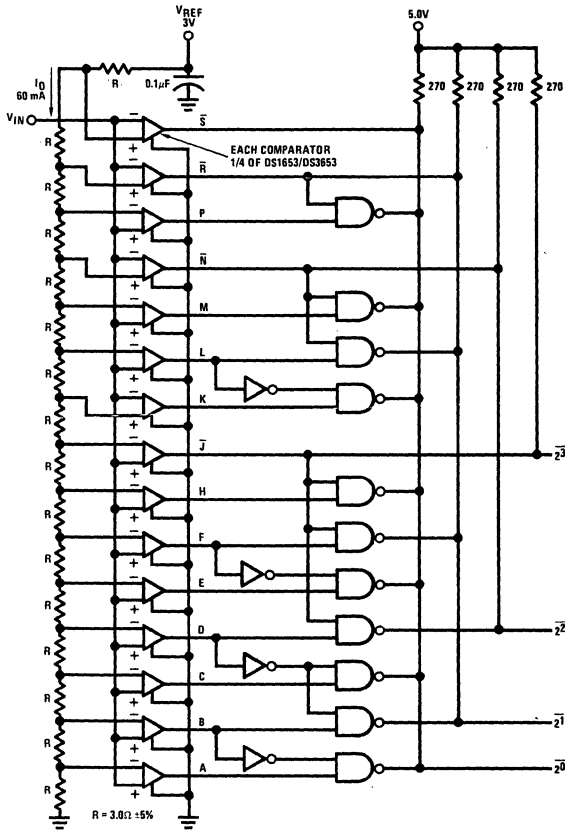


DS1653/DS3653



Typical Applications (Continued)

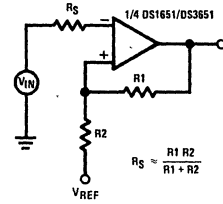
4-Bit Parallel A/D Converter



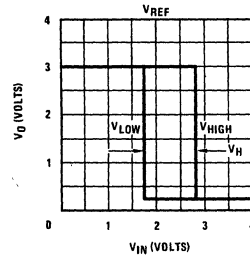
$$\begin{aligned} \overline{2^0} &= (\overline{A} + B) (\overline{C} + D) (\overline{E} + F) (\overline{H} + J) (\overline{K} + L) (\overline{M} + N) (\overline{P} + R) (\overline{S}) \\ \overline{2^1} &= (\overline{B} + D) (\overline{F} + J) (\overline{L} + N) (\overline{R}) \\ \overline{2^2} &= (\overline{D} + J) (\overline{N}) \\ \overline{2^3} &= \overline{J} \end{aligned}$$

Conversion time ≈ 50 ns

Level Detector with Hysteresis



Transfer Characteristics and Equations for Level Detector with Hysteresis



$$V_{HIGH} = V_{REF} + \frac{R_2 [V_{O(MAX)} - V_{REF}]}{R_1 + R_2}$$

$$V_{LOW} = V_{REF} + \frac{R_2 [V_{O(MIN)} - V_{REF}]}{R_1 + R_2}$$

Hysteresis Loop (V_H)

$$V_H = V_{HIGH} - V_{LOW} = \frac{R_2}{R_1 + R_2} [V_{O(MAX)} - V_{O(MIN)}]$$

DS1671/DS3671 Bootstrapped Two Phase MOS Clock Driver

General Description

The DS1671/DS3671 is a high speed dual MOS clock driver and interface circuit. Unique circuit design provides both very high speed operation and the ability to drive large capacitive loads. The device accepts standard TTL outputs and converts them to MOS logic levels. It may be driven from standard 54/74 and 54S/74S series gates and flip-flops or from drivers such as the DS8830 or DM7440. The circuit can be used in both P-channel and N-channel MOS memory system drive applications.

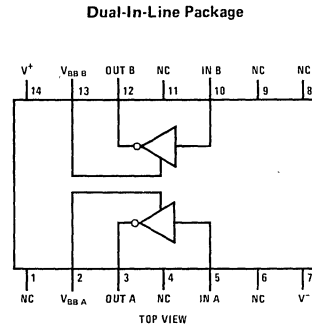
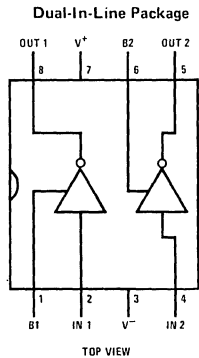
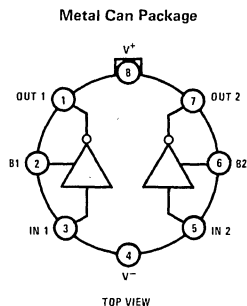
The DS1671/DS3671 is intended to fulfill a wide variety of MOS interface requirements. As a MOS clock driver for long silicon gate shift registers, a single device can drive over 10k bits at 5 MHz. Six devices provide input address and precharge drive for an 8k by 16-bit 1103 RAM memory system.

Each driver uses output bootstrapping to provide a higher voltage to the output stage, thus eliminating the need for an additional V_{DD} supply. The bootstrapping function is accomplished by connecting a small value capacitor (typically 200 pF) from each output to each drivers bootstrap node.

Features

- Fast rise and fall times—20 ns with 1000 pF load
- High output swing—20V
- High output current drive— $\pm 1.5A$
- TTL compatible inputs
- High rep rate—5 to 10 MHz depending on power dissipation
- Low power consumption in MOS "0" state—2 mW
- Swings to 0.4V of GND for RAM address drive

Connection Diagrams

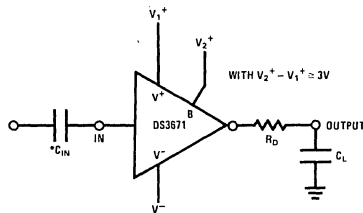


Order Number DS1671H or DS3671H
See NS Package H08C

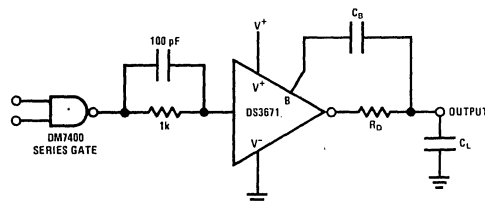
Order Number DS1671J-8, DS3671J-8
or DS3671N
See NS Package J08A or N08A

Order Number DS1671J
or DS3671J
See NS Package J14A

Typical Applications



**DS3671 Operating with Extra Supply
to Inhance Output Voltage Level**



Bootstrap Clock Driver Driven from a TTL Gate

Absolute Maximum Ratings (Note 1)

$V^+ - V^-$ Differential	22V
$V_B - V^-$ Differential	40V
$V_B - V^+$ Differential	20V
Input Voltage ($V_{IN} - V^-$)	5.5V
Input Current	100 mA
Peak Output Current	1.5A
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C
Maximum Power Dissipation* at 25°C	
Cavity Package (8-Pin)	1150 mW
Cavity Package (14-Pin)	1380 mW
Molded Package	1040 mW
Metal Can (TO-5) Package	660 mW

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage			
$V^+ - V^-$ Differential	20		V
$V_B - V^-$ Differential	40		V
$V_B - V^+$ Differential	20		V
Operating Temperature Range			
DS3671	0	+70	°C
DS1671	-55	+125	°C

*Derate 8-pin cavity package 7.7 mW/°C above 25°C; derate 14-pin cavity package 9.3 mW/°C above 25°C; derate molded package 8.4 mW/°C above 25°C; derate metal can (TO-5) package 4.4 mW/°C above 25°C.

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS	
V_{IH}	Logical "1" Input Voltage	$V^- = 0V$	2.0	1.5		V	
I_{IH}	Logical "1" Input Current	$V_{IN} - V^- = 2.4V$		10	15	mA	
V_{IL}	Logical "0" Input Voltage	$V^- = 0V$		0.6	0.4	V	
I_{IL}	Logical "0" Input Current	$V_{IN} - V^- = 0V$		-3	-10	μA	
V_{OH}	Logical "1" Output Voltage	$V_B \geq V^+ + 1.0V, V_{IN} - V^- \equiv 0.4V, I_O = 0 \text{ mA}$	DS3671	$V^+ - 1.0$	$V^+ - 0.75$		V
			DS1671	$V^+ - 1.2$	$V^+ - 0.75$		V
V_{OL}	Logical "0" Output Voltage	$V_{IN} - V^- = 2.4V, I_O = 0 \text{ mA}$		$V^- + 0.6$	$V^- + 1.0$	V	
R_B	Bootstrap Control Resistor		1.1	2.0	3.3	kΩ	
$I_{CC(ON)}$	Supply Current One Side "ON"	$V^+ - V^- = 20V, V_{IN} - V^- = 2.4V, V_B = V^+$		30	40	mA	
$I_{CC(OFF)}$	Supply Current "OFF"	$V^+ - V^- = 20V, V_{IN} - V^- = 0V$	DS3671	10	100	μA	
			DS1671	50	500	μA	

Switching Characteristics $T_A = 25^\circ\text{C}, V^+ = 20V, V^- = 0V$

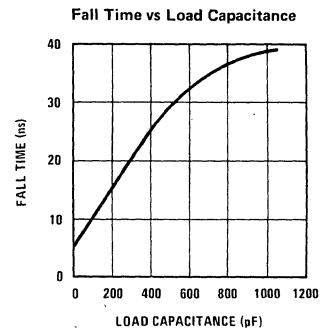
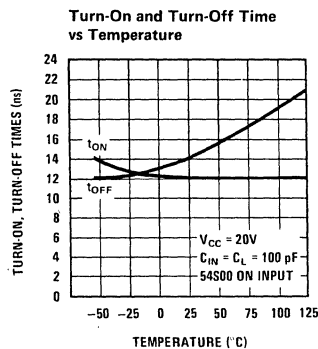
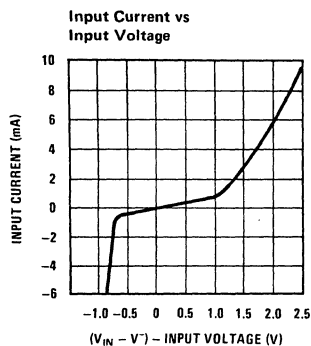
PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
t_{pd0}	Propagation Delay to a Logical "0"	$R_D = 10\Omega, C_L = 1000 \text{ pF}$		7.5	15	ns
t_{pd1}	Propagation Delay to a Logical "1"	$R_D = 10\Omega, C_L = 1000 \text{ pF}$		12	15	ns
t_r	Rise Time	$R_D = 10\Omega, C_L = 500 \text{ pF}$ $C_L = 1000 \text{ pF}$		25	35	ns
				31	40	ns
t_f	Fall Time	$R_D = 10\Omega, C_L = 500 \text{ pF}$ $C_L = 1000 \text{ pF}$		30	40	ns
				38	50	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

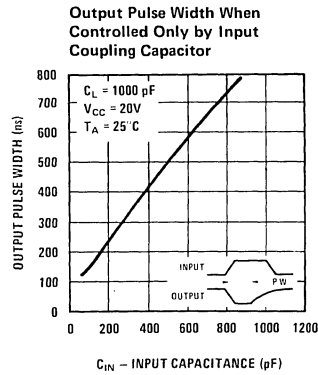
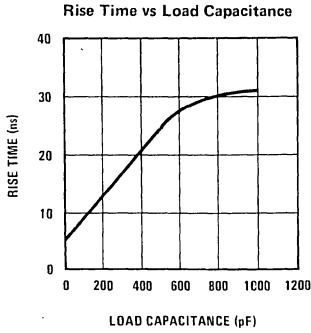
Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS1671 and across the 0°C to +70°C range for the DS3671. All typicals at 25°C.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

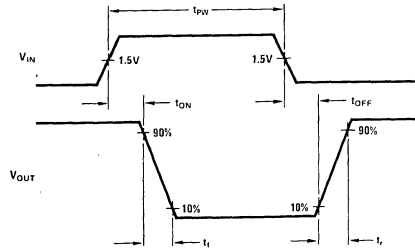
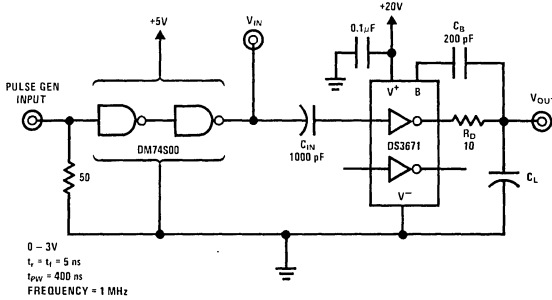
Typical Performance Characteristics



Typical Performance Characteristics (Continued)

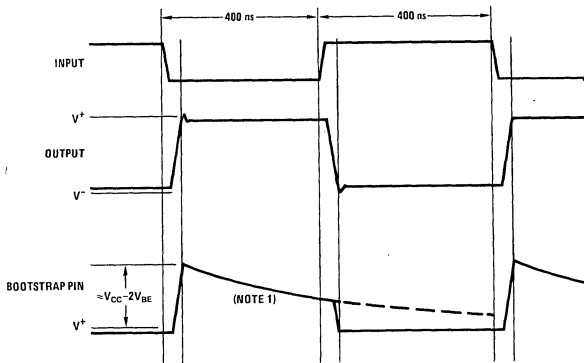


AC Test Circuit and Switching Time Waveforms



6

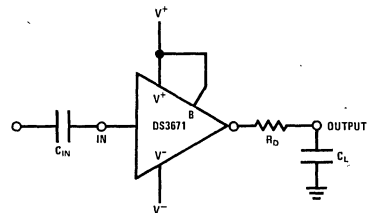
Node Voltage Waveforms



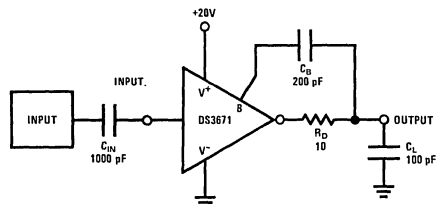
Note 1: The fall time has an exponential decay with the following time constant: $t_B = C_B R_B$. The range of values for R_B (resistor tolerance, and temperature coefficient included) can be found in the table of electrical characteristics.

Note 2: The high current transient (as high as 1.5A) through the resistance of the external interconnecting V⁺ lead during the output transition from the high state to the low state can appear as negative feedback to the input. If the external interconnecting lead from the driving circuit to V⁺ is electrically long, or has significant DC resistance, it can subtract from the switching response.

Typical Applications (Continued)

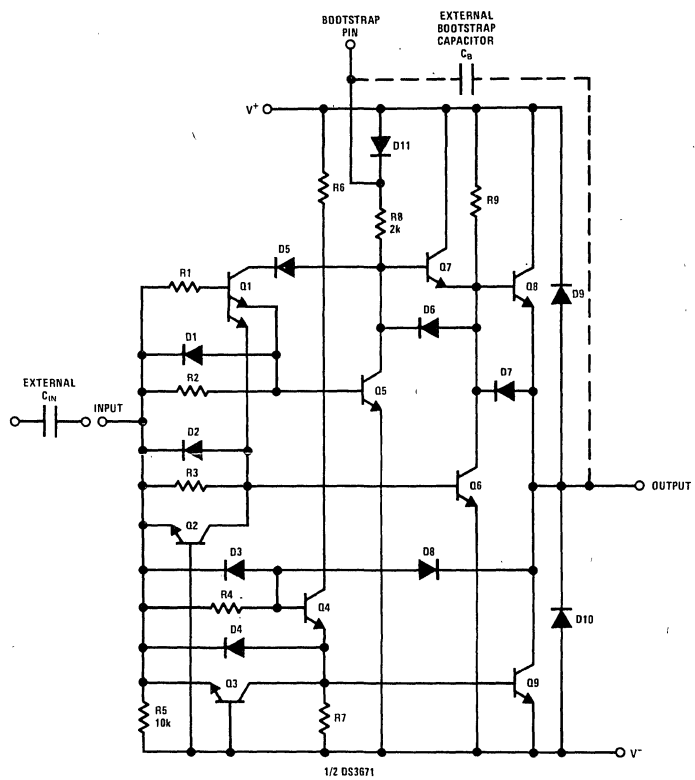


DS3671 Connected as DS0026 with Equivalent Characteristics



Typical Bootstrap

Schematic Diagram (One Driver)



DS3685 Hex TRI-STATE® Latch

General Description

The DS3685 is a hex latch. PNP input transistors are used to reduce input currents, allowing large fan-out to these drivers. The circuit has Schottky-clamped transistor logic for minimum propagation delay, and TRI-STATE outputs which allow bus operation.

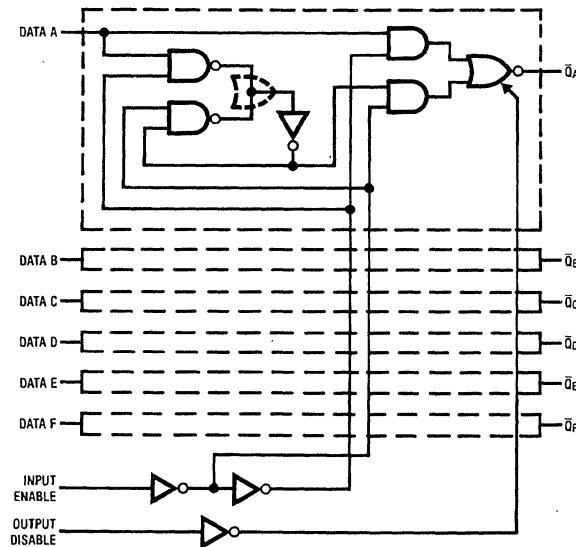
The circuit employs a fall-through latch which captures the data in parallel with the output, thereby eliminating the delay normally encountered in other latch circuits.

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Features

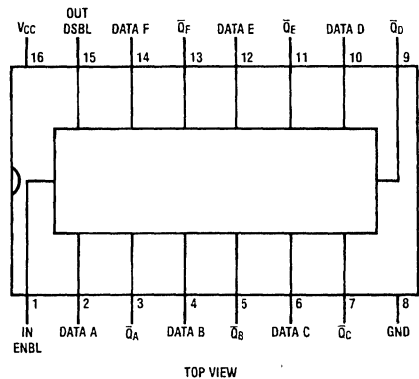
- TTL/LS compatible inputs
- PNP inputs minimize loading
- TRI-STATE outputs
- Fall-through latch design
- Minimum skew

Logic and Connection Diagrams



TL/F/5220-1

Dual-In-Line Package



TOP VIEW

TL/F/5220-2

Order Number DS3685J or DS3685N
See NS Package J16A or N16A

6

Truth Table

Input Enable	Output Disable	Data	Output	Operation
1	0	1	0	Data Feed-Through
1	0	0	1	Data Feed-Through
0	0	X	Q	Latched to Data Present when Enable Went Low
X	1	X	Hi-Z	High Impedance Output

X = don't care

Hi-Z = TRI-STATE mode

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7V
Logical "1" Input Voltage	7V
Logical "0" Input Voltage	-1.5V
Storage Temperature Range	-65°C to 150°C
Lead Temperature (Soldering, 10 seconds)	300°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1433 mW
Molded Package	1362 mW

*Derate cavity package 9.6 mW/°C above 25°C; derate molded package 10.9 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	4.5	5.5	V
Temperature (T_A)	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

Parameter	Conditions	Min	Typ	Max	Units	
$V_{IN(1)}$ Logical "1" Input Voltage		2.0			V	
$V_{IN(0)}$ Logical "0" Input Voltage				0.8	V	
$I_{IN(1)}$ Logical "1" Input Current	$V_{IN} = 5.5V, V_{CC} = \text{Max}$	Enable Inputs		0.1	40	μA
		Data Inputs		0.2	80	μA
$I_{IN(0)}$ Logical "0" Input Current	$V_{IN} = 0.5V, V_{CC} = \text{Max}$	Enable Inputs		-50	-300	μA
		Data Inputs		-100	-500	μA
V_{CLAMP} Input Clamp Voltage	$V_{CC} = \text{Min}, I_{IN} = -18 \text{ mA}$		-0.75	-1.2	V	
I_{OS} Output Short-Circuit Current	$V_{CC} = \text{Max}, V_{OUT} = 0V, (\text{Note } 4)$	-40		-100	mA	
V_{OH} Logical "1" Output Voltage	$V_{CC} = \text{Min}$	$I_{OH} = -1 \text{ mA}$	2.5	3.5		V
		$I_{OH} = -10 \mu\text{A}$	2.8	3.8		V
V_{OL} Logical "0" Output Voltage	$V_{CC} = \text{Min}$	$I_{OL} = 20 \text{ mA}$		0.4	0.5	V
		$I_{OL} = 10 \mu\text{A}$		0.25	0.35	V
I_{HZ} TRI-STATE Output Current	$V_{OUT} = 0.4V \text{ to } 2.4V, \text{ Output Disable} = 2V$	-40		40	μA	
I_{CC} Power Supply Current	$V_{CC} = \text{Max}, \text{ All Inputs} = 3V = 0V, \text{ Enable} = 3V$			90	mA	

Switching Characteristics $V_{CC} = 5V, T_A = 25^\circ\text{C}$, unless otherwise noted.

Parameter	Conditions	Min	Typ	Max	Units
t_{PHL} Propagation Delay Time Low-to-High Level Output	$C_L = 15 \text{ pF}, R_L = 280\Omega, (\text{Figures } 1 \text{ and } 2)$		5.5	7.0	ns
t_{PLH} Propagation Delay Time, High-to-Low Level Output	$C_L = 15 \text{ pF}, R_L = 280\Omega, (\text{Figures } 1 \text{ and } 2)$		4.5	6.0	ns
t_{PHL} Propagation Delay Time, Low-to-High Level Output	$C_L = 50 \text{ pF}, R_L = 280\Omega, (\text{Figures } 1 \text{ and } 2)$		8		ns
t_{PLH} Propagation Delay Time, High-to-Low Level Output	$C_L = 50 \text{ pF}, R_L = 280\Omega, (\text{Figures } 1 \text{ and } 2)$		6		ns
t_{SET-UP} Set-Up Time on Data Input Before Input Enable Goes Low		10	0		ns
t_{HOLD} Hold Time on Data Input After Input Enable Goes Low		0			ns
t_{ZL} Delay from Disable Input to Logical "0" Level (from High Impedance State)	$C_L = 15 \text{ pF}, (\text{Figures } 1 \text{ and } 3)$		8.2	15	ns
t_{ZH} Delay from Disable Input to Logical "1" Level (from High Impedance State)	$C_L = 15 \text{ pF}, (\text{Figures } 1 \text{ and } 3)$		17	24	ns
t_{LZ} Delay from Disable Input to High Impedance State (from Logical "0" Level)	$C_L = 15 \text{ pF}, (\text{Figures } 1 \text{ and } 4)$		7.7	14	ns
t_{HZ} Delay from Disable Input to High Impedance State (from Logical "1" Level)	$C_L = 15 \text{ pF}, (\text{Figures } 1 \text{ and } 4)$		5.5	12	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS3685. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5V$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output should be shorted at one time.

AC Test Circuit and Switching Time Waveforms

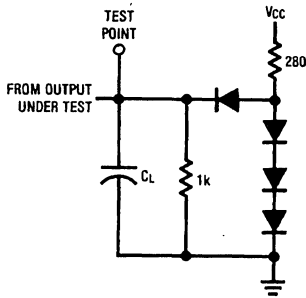


FIGURE 1

TL/F/5220-3

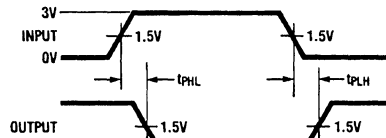


FIGURE 2

TL/F/5220-4

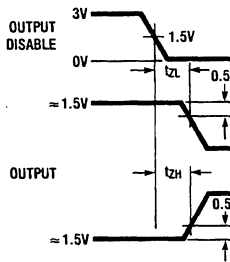


FIGURE 3

TL/F/5220-5

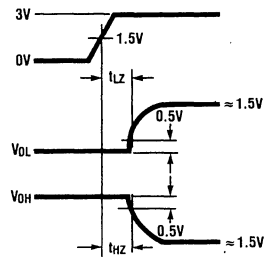
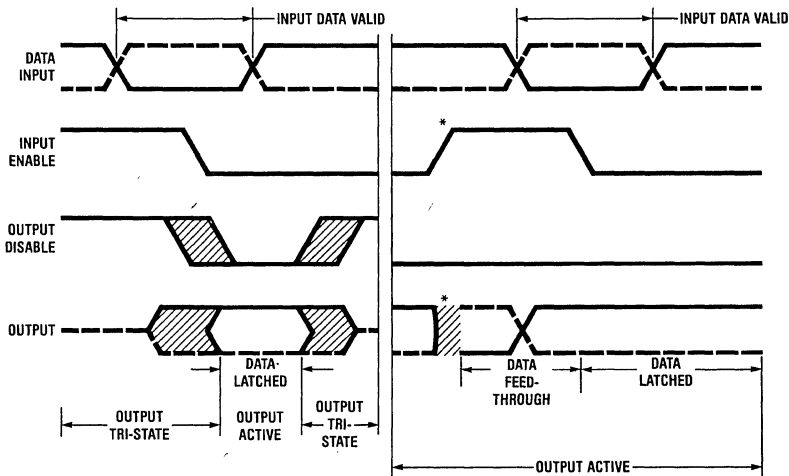


FIGURE 4

TL/F/5220-6

Input characteristics: PRR ≤ 1 MHz, Z_{OUT} = 50Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.

Operating Waveforms



TL/F/5220-7

*When the Input Enable makes a positive transition the output will be indeterminate for a short duration. The positive transition of the Input Enable normally occurs during a don't-care timing state at the output.

DS16149/DS36149, DS16179/DS36179 Hex MOS Drivers

General Description

The DS16149/DS36149 and DS16179/DS36179 are Hex MOS drivers with outputs designed to drive large capacitive loads up to 500 pF associated with MOS memory systems. PNP input transistors are employed to reduce input currents allowing the large fan-out to these drivers needed in memory systems. The circuit has Schottky-clamped transistor logic for minimum propagation delay, and a disable control that places the outputs in the logic "1" state (see truth table). This is especially useful in MOS RAM applications where a set of address lines has to be in the logic "1" state during refresh.

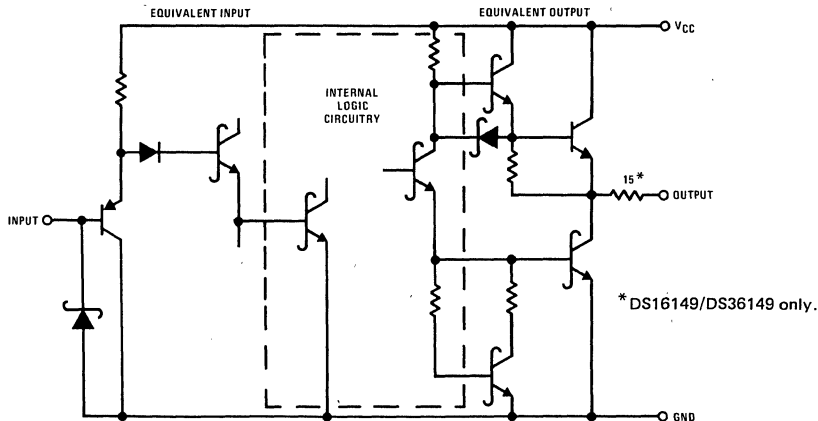
The DS16149/DS36149 has a 15 Ω resistor in series with the outputs to dampen transients caused by the fast-

switching output. The DS16179/DS36179 has a direct low impedance output for use with or without an external resistor.

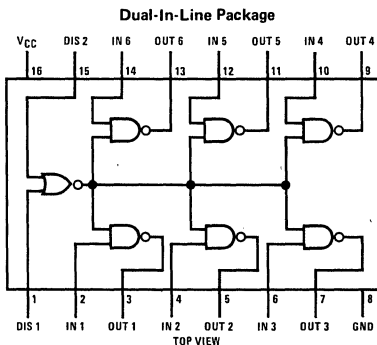
Features

- High speed capabilities
 - Typ 9 ns driving 50 pF
 - Typ 29 ns driving 500 pF
- Built-in 15 Ω damping resistor (DS16149/DS36149)
- Same pin-out as DM8096 and DM74366

Schematic Diagram



Connection Diagram



Truth Table

DISABLE INPUT		INPUT	OUTPUT
DIS 1	DIS 2		
0	0	0	1
0	0	1	0
0	1	X	1
1	0	X	1
1	1	X	1

X = Don't care

Order Number DS16149J, DS36149J, DS16179J,
DS36179J, DS36149N or DS36179N
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Logical "1" Input Voltage	7.0V
Logical "0" Input Voltage	-1.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1371 mW
Molded Package	1280 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 9.1 mW/°C above 25°C; derate molded package 10.2 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})	4.5	5.5	V
Temperature (T _A)			
DS16149, DS16179	-55	+125	°C
DS36149, DS36179	0	+70	°C

DC Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
V _{IN(1)}	Logical "1" Input Voltage			2.0			V
V _{IN(0)}	Logical "0" Input Voltage					0.8	V
I _{IN(1)}	Logical "1" Input Current	V _{CC} = 5.5V	V _{IN} = 5.5V		0.1	40	μA
I _{IN(0)}	Logical "0" Input Current	V _{CC} = 5.5V	V _{IN} = 0.5V		-50	-250	μA
V _{CLAMP}	Input Clamp Voltage	V _{CC} = 4.5V	I _{IN} = -18 mA		-0.75	-1.2	V
V _{OH}	Logical "1" Output Voltage (No Load)	V _{CC} = 4.5V	I _{OH} = -10 μA	DS16149/DS16179	3.4	4.3	V
				DS36149/DS36179	3.5	4.3	V
V _{OL}	Logical "0" Output Voltage (No Load)	V _{CC} = 4.5V	I _{OL} = 10 μA	DS16149/DS16179	0.25	0.4	V
				DS36149/DS36179	0.25	0.35	V
V _{OH}	Logical "1" Output Voltage (With Load)	V _{CC} = 4.5V	I _{OH} = -1.0 mA	DS16149	2.4	3.5	V
				DS16179	2.5	3.5	V
				DS36149	2.6	3.5	V
				DS36179	2.7	3.5	V
V _{OL}	Logical "0" Output Voltage (With Load)	V _{CC} = 4.5V	I _{OL} = 20 mA	DS16149	0.6	1.1	V
				DS16179	0.4	0.5	V
				DS36149	0.6	1.0	V
				DS36179	0.4	0.5	V
I _{ID}	Logical "1" Drive Current	V _{CC} = 4.5V	V _{OUT} = 0V, (Note 4)		-250		mA
I _{OD}	Logical "0" Drive Current	V _{CC} = 4.5V	V _{OUT} = 4.5V, (Note 4)		150		mA
I _{CC}	Power Supply Current	V _{CC} = 5.5V	Disable Inputs = 0V		33	60	mA
			All Other Inputs = 3V				
			All Inputs = 0V		14	20	mA

Switching Characteristics (V_{CC} = 5V, T_A = 25°C) (Note 4)

PARAMETER		CONDITIONS		MIN	TYP	MAX	UNITS
t _{S-}	Storage Delay Negative Edge	(Figure 1)	C _L = 50 pF		4.5	7	ns
			C _L = 500 pF		7.5	12	ns
t _{S+}	Storage Delay Positive Edge	(Figure 1)	C _L = 50 pF		5	8	ns
			C _L = 500 pF		8	13	ns
t _F	Fall Time	(Figure 1)	C _L = 50 pF		5	8	ns
			C _L = 500 pF		22	35	ns
t _R	Rise Time	(Figure 1)	C _L = 50 pF		6	9	ns
			C _L = 500 pF		26	35	ns
t _{LH}	Delay from Disable Input to Logical "1"		R _L = 2 kΩ to Gnd, C _L = 50 pF, (Figure 2)		15	22	ns
t _{HL}	Delay from Disable Input to Logical "0"		R _L = 2 kΩ to V _{CC} , C _L = 50 pF, (Figure 3)		11	18	ns

Notes

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to $+125^{\circ}\text{C}$ temperature range for the DS16149 and DS16179 and across the 0°C to $+70^{\circ}\text{C}$ range for the DS36149 and DS36179. All typical values are for $T_A = 25^{\circ}\text{C}$ and $V_{CC} = 5\text{V}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: When measuring output drive current and switching response for the DS16179 and DS36179 a $15\ \Omega$ resistor should be placed in series with each output. This resistor is internal to the DS16149/DS36149 and need not be added.

AC Test Circuits and Switching Time Waveforms

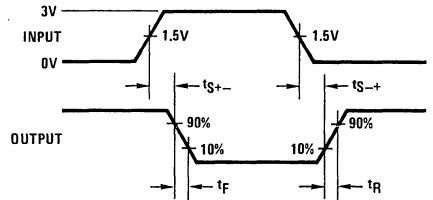
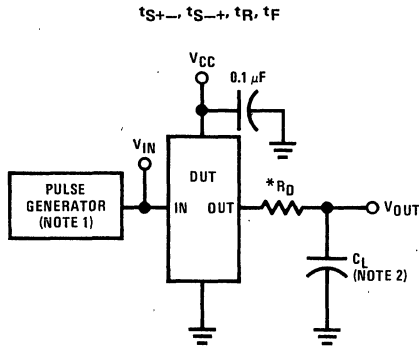


FIGURE 1

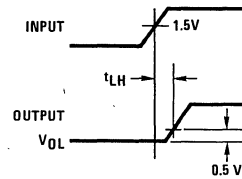
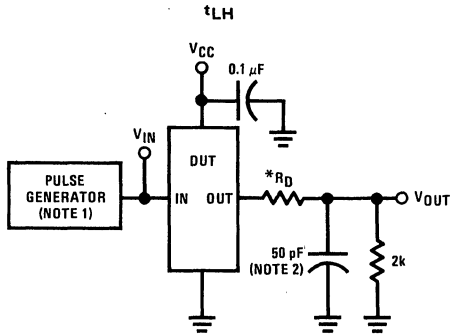


FIGURE 2

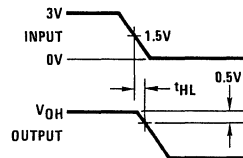
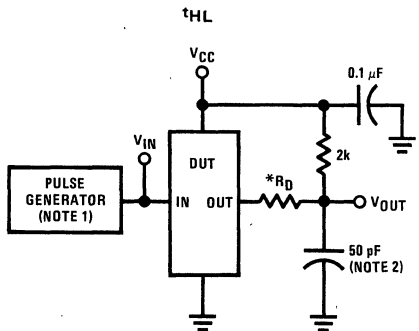


FIGURE 3

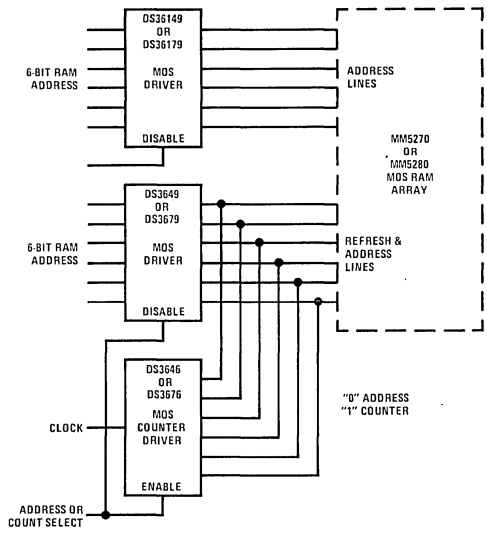
*Internal on DS16149 and DS36149

Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\ \Omega$ and $PRR \leq 1\ \text{MHz}$. Rise and fall times between 10% and 90% points $\leq 5\ \text{ns}$.

Note 2: C_L includes probe and jig capacitance.



Typical Application



DS55325/DS75325 Memory Drivers

General Description

The DS55325 and DS75325 are monolithic memory drivers which feature high current outputs as well as internal decoding of logic inputs. These circuits are designed for use with magnetic memories.

The circuit contains two 600 mA sink-switch pairs and two 600 mA source-switch pairs. Inputs A and B determine source selection while the source strobe (S_1) allows the selected source turn on. In the same manner, inputs C and D determine sink selection while the sink strobe (S_2) allows the selected sink turn on.

Sink-output collectors feature an internal pull-up resistor in parallel with a clamping diode connected to V_{CC2} . This protects the outputs from voltage surges associated with switching inductive loads.

The source stage features Node R which allows extreme flexibility in source current selection by controlling the amount of base drive to each source transistor. This method of setting the base drive brings the power associated with the resistor outside the package thereby allowing the circuit to

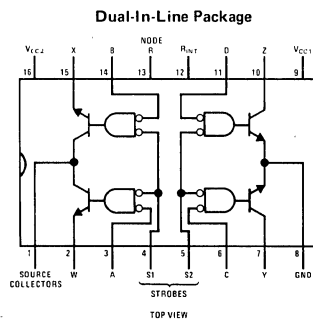
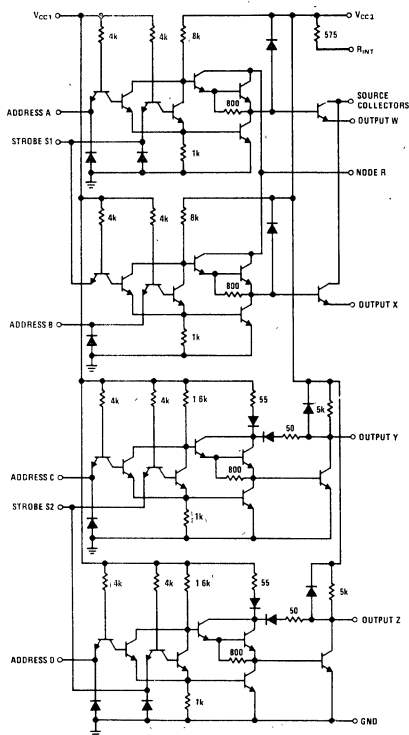
operate at higher source currents for a given junction temperature. If this method of source current setting is not desired, then Nodes R and R_{INT} can be shorted externally activating an internal resistor connected from V_{CC2} to Node R. This provides adequate base drive for source currents up to 375 mA with $V_{CC2} = 15V$ or 600 mA with $V_{CC2} = 24V$.

The DS55325 operates over the fully military temperature range of $-55^{\circ}C$ to $+125^{\circ}C$, while the DS75325 operates from $0^{\circ}C$ to $+70^{\circ}C$.

Features

- 600 mA output capability
- 24V output capability
- Dual sink and dual source outputs
- Fast switching times
- Source base drive externally adjustable
- Input clamping diodes
- TTL compatible

Schematic and Connection Diagrams



Order Number DS55325J, DS75325J,
or DS75325N
See NS Package J14A or N14A

Truth Table

ADDRESS INPUTS			STROBE INPUTS		OUTPUTS				
SOURCE	SINK		SOURCE	SINK	SOURCE	SINK	SOURCE	SINK	
A	B	C	D	S1	S2	W	X	Y	Z
L	H	X	X	L	H	ON	OFF	OFF	OFF
H	L	X	X	L	H	OFF	ON	OFF	OFF
X	X	L	H	H	L	OFF	OFF	ON	OFF
X	X	H	L	H	L	OFF	OFF	OFF	ON
X	X	X	X	H	H	OFF	OFF	OFF	OFF
H	H	H	H	X	X	OFF	OFF	OFF	OFF

H = high level, L = low level, X = irrelevant
NOTE: Not more than one output is to be on at any one time.

Absolute Maximum Ratings (Note 1)

Supply Voltage V_{CC1} (Note 5)	7V
Supply Voltage V_{CC2} (Note 5)	25V
Input Voltage (Any Address or Strobe Input)	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Temperature (T_A)			
DS55325	-55	+125	°C
DS75325	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS		
V_{IH}	High Level Input Voltage	(Figures 1 and 2)	2			V		
V_{IL}	Low Level Input Voltage	(Figures 3 and 4)			0.8	V		
V_I	Input Clamp Voltage	$V_{CC1} = 4.5V$, $V_{CC2} = 24V$, $I_{IN} = -12\text{ mA}$, $T_A = 25^\circ\text{C}$, (Figure 5)		-1.3	-1.7	V		
I_{OFF}	Source Collectors Terminal "OFF" State Current	$V_{CC1} = 4.5V$, $V_{CC2} = 24V$, (Figure 1)	Full Range	DS55325		500	μA	
				DS75325		200	μA	
		$T_A = 25^\circ\text{C}$	DS55325		3	150	μA	
			DS75325		3	200	μA	
V_{OH}	High Level Sink Output Voltage	$V_{CC1} = 4.5V$, $V_{CC2} = 24V$, $I_{OUT} = 0$, (Figure 2)	19	23		V		
V_{SAT}	Saturation Voltage Source Outputs	$V_{CC1} = 4.5V$, $V_{CC2} = 15V$, $R_L = 24\Omega$, $I_{SOURCE} \approx -600\text{ mA}$, (Figure 3), (Notes 4 and 6)	Full Range			0.9	V	
			$T_A = 25^\circ\text{C}$	DS55325		0.43	0.7	V
				DS75325		0.43	0.75	V
V_{SAT}	Saturation Voltage Sink Outputs	$V_{CC1} = 4.5V$, $V_{CC2} = 15V$, $R_L = 24\Omega$, $I_{SINK} \approx 600\text{ mA}$, (Figure 4), (Notes 4 and 6)	Full Range			0.9	V	
			$T_A = 25^\circ\text{C}$	DS55325		0.43	0.7	V
				DS75325		0.43	0.75	V
I_I	Input Current at Maximum Input Voltage	$V_{CC1} = 5.5V$, $V_{CC2} = 24V$, $V_I = 5.5V$, (Figure 5)	Address Inputs			1	mA	
			Strobe Inputs			2	mA	
I_{IH}	High Level Input Current	$V_{CC1} = 5.5V$, $V_{CC2} = 24V$, $V_I = 2.4V$, (Figure 5)	Address Inputs			3	40	μA
			Strobe Inputs			6	80	μA
I_{IL}	Low Level Input Current	$V_{CC1} = 5.5V$, $V_{CC2} = 24V$, $V_I = 0.4V$, (Figure 5)	Address Inputs			-1	-1.6	mA
			Strobe Inputs			-2	-3.2	mA
$I_{CC\ OFF}$	Supply Current, All Sources and Sinks "OFF"	$V_{CC1} = 5.5V$, $V_{CC2} = 24V$, $T_A = 25^\circ\text{C}$, (Figure 6)	V_{CC1}			14	22	mA
			V_{CC2}			7.5	20	mA
I_{CC1}	Supply Current From V_{CC1} , Either Sink "ON"	$V_{CC1} = 5.5V$, $V_{CC2} = 24V$, $I_{SINK} = 50\text{ mA}$, $T_A = 25^\circ\text{C}$, (Figure 7)		55	70	mA		
I_{CC2}	Supply Current From V_{CC2} , Either Source "ON"	$V_{CC1} = 5.5V$, $V_{CC2} = 24V$, $I_{SOURCE} = -50\text{ mA}$, $T_A = 25^\circ\text{C}$, (Figure 8)		32	50	mA		

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DS55325 and across the 0°C to +70°C range for the DS75325. All typical values are at $T_A = 25^\circ\text{C}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

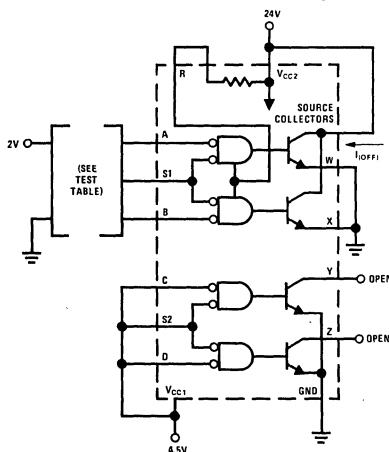
Note 5: Voltage values are with respect to network ground terminal.

Note 6: These parameters must be measured using pulse techniques. $t_{PW} = 200\mu\text{s}$, duty cycle $\leq 2\%$.

Switching Characteristics ($V_{CC1} = 5V, T_A = 25^\circ C$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t_{PLH} Propagation Delay Time, Low-to-High Level Output	$V_{CC2} = 15V, R_L = 24\Omega, C_L = 25\text{ pF},$ (Figure 9)	Source Collectors	25	50	ns
		Sink Outputs	20	45	ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output	$V_{CC2} = 15V, R_L = 24\Omega, C_L = 25\text{ pF},$ (Figure 9)	Source Collectors	25	50	ns
		Sink Outputs	20	45	ns
t_{TLH} Transition Time, Low-to-High Level Output	$C_L = 25\text{ pF}$	Source Outputs, $V_{CC2} = 20V, R_L = 1\text{ k}\Omega,$ (Figure 10)	55		ns
		Sink Outputs, $V_{CC2} = 15V, R_L = 24\Omega,$ (Figure 9)	7	15	ns
t_{THL} Transition Time, High-to-Low Level Output	$C_L = 25\text{ pF}$	Source Outputs, $V_{CC2} = 20V, R_L = 1\text{ k}\Omega,$ (Figure 10)	7		ns
		Sink Outputs, $V_{CC2} = 15V, R_L = 24\Omega,$ (Figure 9)	9	20	ns
t_s Storage Time, Sink Outputs	$V_{CC2} = 15V, R_L = 24\Omega, C_L = 25\text{ pF},$ (Figure 9)		15	30	ns

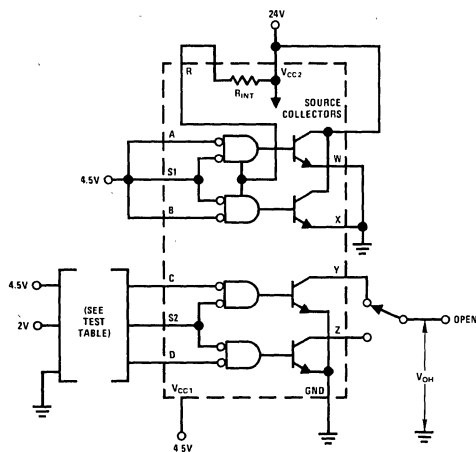
DC Test Circuits



TEST TABLE

A	B	S1
GND	GND	2V
2V	2V	GND

FIGURE 1. I_{OFF}

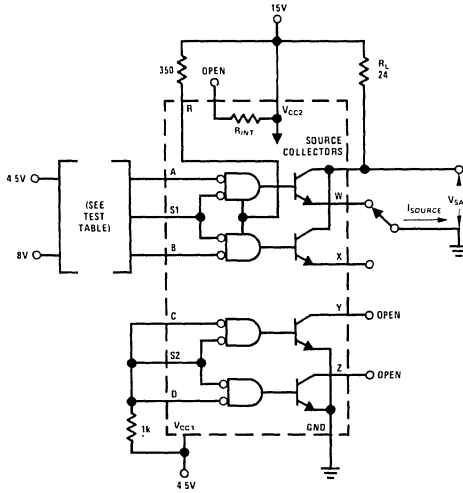


TEST TABLE

C	D	S2	Y	Z
2V	4.5V	GND	V_{OH}	OPEN
GND	4.5V	2V	V_{OH}	OPEN
4.5V	2V	GND	OPEN	V_{OH}
4.5V	GND	2V	OPEN	V_{OH}

FIGURE 2. V_{IH} and V_{OH}

DC Test Circuits (Continued)

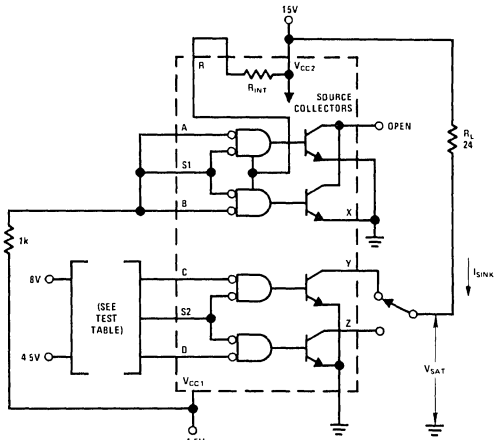


Note 1: Figures 3 and 4 parameters must be measured using pulse techniques. $t_{UV} = 200\mu s$, duty cycle $\leq 2\%$.

TEST TABLE

A	B	S1	W	X
0.8V	4.5V	0.8V	GND	OPEN
4.5V	0.8V	0.8V	OPEN	GND

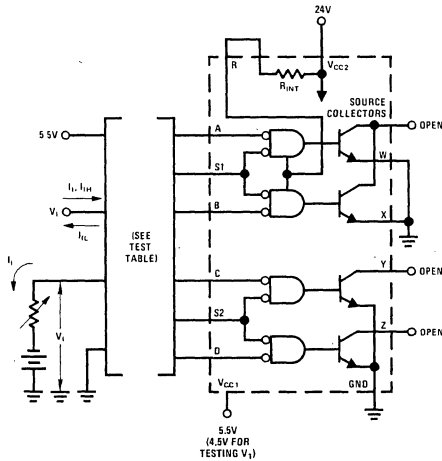
FIGURE 3. V_{IL} and Source V_{SAT}



TEST TABLE

C	D	S2	Y	Z
0.8V	4.5V	0.8V	R_L	OPEN
4.5V	0.8V	0.8V	OPEN	R_L

FIGURE 4. V_{IL} and Sink V_{SAT}



I_I, I_{IH}

TEST TABLES

V_I, I_{IL}

APPLY $V_I = 5.5V$ MEASURE I_I	GROUND	APPLY 5.5V
APPLY $V_I = 2.4V$ MEASURE I_{IH}		
A	S1	B, C, S2, D
S1	A, B	C, S2, D
B	S1	A, C, S2, D
C	S2	A, S1, B, D
S2	C, D	A, S1, B
D	S2	A, S1, B, C

APPLY $V_I = 0.4V$, MEASURE I_{IL}	APPLY 5.5V
APPLY $I_I = -10 mA$, MEASURE V_I	
A	S1, B, C, S2, D
S1	A, B, C, S2, D
B	A, S1, C, S2, D
C	A, S1, B, S2, D
S2	A, S1, B, C, D
D	A, S1, B, C, S2

FIGURE 5. V_I, I_I, I_{IH} , and I_{IL}

DC Test Circuits (Continued)

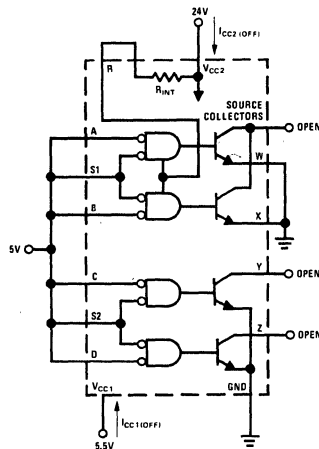
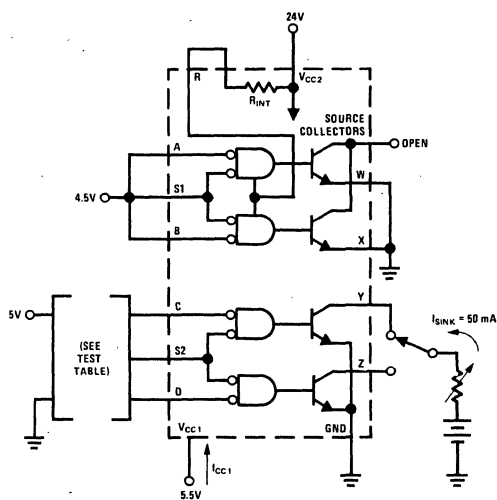


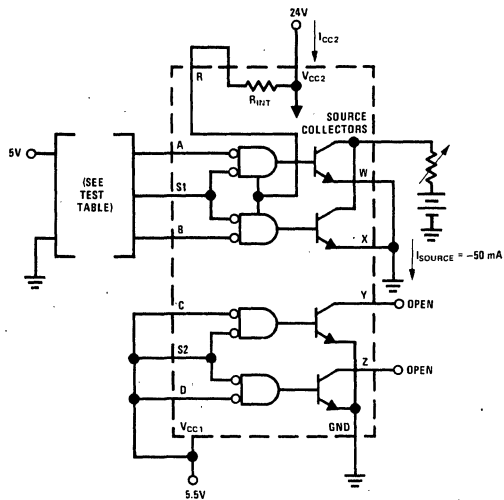
FIGURE 6. I_{CC1}(OFF) and I_{CC2}(OFF)



TEST TABLE

C	D	S2	Y	Z
GND	5V	GND	I _(SINK)	OPEN
5V	GND	GND	OPEN	I _(SINK)

FIGURE 7. I_{CC1}, Either Sink On

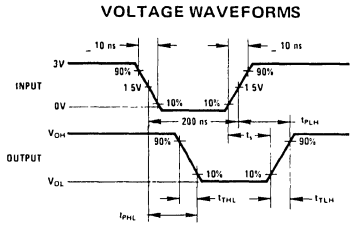
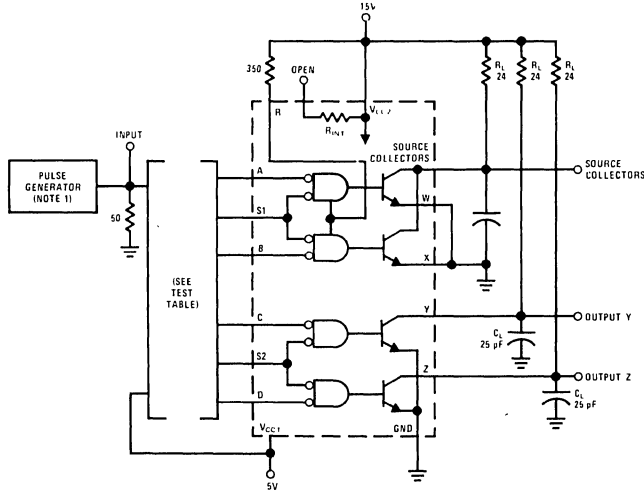


TEST TABLE

A	B	S1
GND	5V	GND
5V	GND	GND

FIGURE 8. I_{CC2}, Either Source On

DC Test Circuits (Continued)

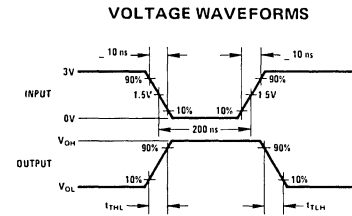
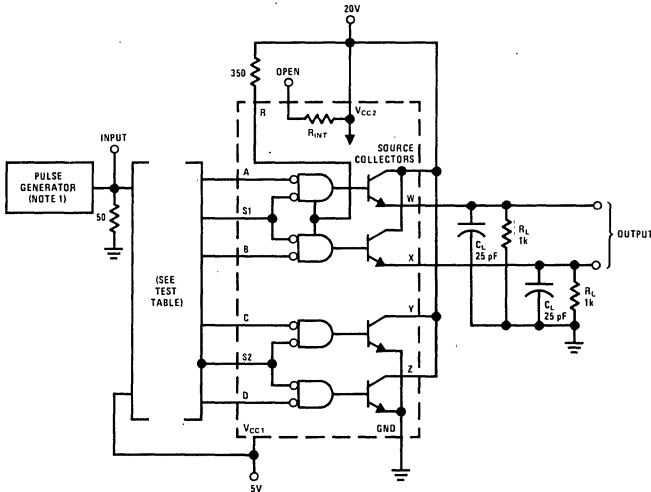


Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\Omega$, duty cycle $\leq 1\%$.
 Note 2: C_L includes probe and jig capacitance

TEST TABLE

PARAMETER	OUTPUT UNDER TEST	INPUT	CONNECT TO 5V
t_{PLH} and t_{PHL}	Source collectors	A and S1 B and S1	B, C, D and S2 A, C, D and S2
t_{PLH} , t_{PHL} , t_{TLH} , t_{THL} , and t_s	Sink output Y	C and S2	A, B, D and S1
	Sink output Z	D and S2	A, B, C and S1

FIGURE 9. Switching Times



Note 1: The pulse generator has the following characteristics: $Z_{OUT} = 50\Omega$, duty cycle $\leq 1\%$.
 Note 2: C_L includes probe and jig capacitance.

TEST TABLE

PARAMETER	OUTPUT UNDER TEST	INPUT	CONNECT TO 5V
t_{TLH} and t_{THL}	Source output W Source output X	A and S1 B and S1	B, C, D, and S2 A, C, D, and S2

FIGURE 10. Transition Times of Source Outputs

Applications

External Resistor Calculation

A typical magnetic-memory word drive requirement is shown in Figure 11. A source-output transistor of one DS75325 delivers load current (I_L). The sink-output transistor of another DS75325 sinks this current.

The value of the external pull-up resistor (R_{ext}) for a particular memory application may be determined using the following equation:

$$R_{ext} = \frac{16 [V_{CC2(min)} - V_S - 2.2]}{I_L - 1.6 [V_{CC2(min)} - V_S - 2.9]} \quad (1)$$

where: R_{ext} is in $k\Omega$,

$V_{CC2(min)}$ is the lowest expected value of V_{CC2} in volts, V_S is the source output voltage in volts with respect to ground, I_L is in mA.

The power dissipated in resistor R_{ext} during the load current pulse duration is calculated using Equation 2.

$$P_{R_{ext}} \approx \frac{I_L}{16} [V_{CC2(min)} - V_S - 2] \quad (2)$$

where: $P_{R_{ext}}$ is in mW.

After solving for R_{ext} , the magnitude of the source collector current (I_{CS}) is determined from Equation 3.

$$I_{CS} \approx 0.94 I_L \quad (3)$$

where: I_{CS} is in mA.

As an example, let $V_{CC2(min)} = 20V$ and $V_L = 3V$ while I_L of 500 mA flows. Using Equation 1:

$$R_{ext} = \frac{16 (20 - 3 - 2.2)}{500 - 1.6 (20 - 3 - 2.9)} = 0.5 k\Omega$$

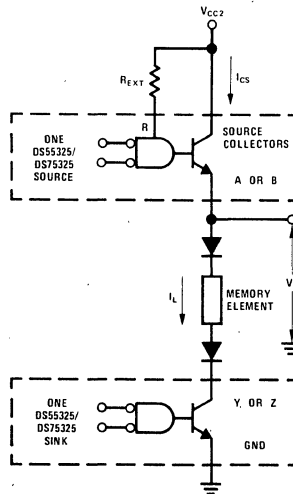
and from Equation 2:

$$P_{R_{ext}} \approx \frac{500}{16} [20 - 3 - 2] \approx 470 mW$$

The amount of the memory system current source (I_{CS}) from Equation 3 is:

$$I_{CS} \approx 0.94 (500) \approx 470 mA$$

In this example the regulated source-output transistor base current through the external pull-up resistor (R_{ext}) and the source gate is approximately 30 mA. This current and I_{CS} comprise I_L .



Note 1: For clarity, partial logic diagrams of two DS55325's are shown.

Note 2: Source and sink shown are in different packages.

FIGURE 11. Typical Application Data

DS75361 Dual TTL-to-MOS Driver

General Description

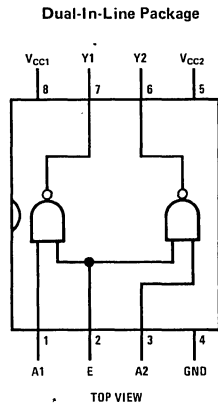
The DS75361 is a monolithic integrated dual TTL-to-MOS driver interface circuit. The device accepts standard TTL input signals and provides high-current and high-voltage output levels for driving MOS circuits. It is used to drive address, control, and timing inputs for several types of MOS RAMs including the 1103 and MM5270 and MM5280.

The DS75361 operates from standard TTL 5V supplies and the MOS V_{SS} supply in many applications. The device has been optimized for operation with V_{CC2} supply voltage from 16V to 20V; however, it is designed for use over a much wider range of V_{CC2} .

Features

- Capable of driving high-capacitance loads
- Compatible with many popular MOS RAMs
- V_{CC2} supply voltage variable over wide range to 24V
- Diode-clamped inputs
- TTL compatible
- Operates from standard bipolar and MOS supplies
- High-speed switching
- Transient overdrive minimizes power dissipation
- Low standby power dissipation

Connection Diagram



Order Number DS75361J-8 or DS75361N
See NS Package J08A or N08A

Absolute Maximum Ratings (Note 1)

Supply Voltage Range of V_{CC1} (Note 1)	-0.5V to 7V
Supply Voltage Range of V_{CC2}	-0.5V to 25V
Input Voltage	5.5V
Inter-Input Voltage (Note 4)	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1022 mW
Lead Temperature 1/16 Inch from Case for 60 Seconds: J Package	300°C
Lead Temperature 1/16 Inch from Case for 10 Seconds: N or P Package	200°C

*Derate molded package 8.2 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC1})	4.75	5.25	V
Supply Voltage (V_{CC2})	4.75	24	V
Operating Temperature (T_A)	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{IH} High-Level Input Voltage		2			V
V_{IL} Low-Level Input Voltage				0.8	V
V_i Input Clamp Voltage	$I_i = -12$ mA			-1.5	V
V_{OH} High-Level Output Voltage	$V_{IL} = 0.8$ V, $I_{OH} = -50$ μ A	$V_{CC2}-1$	$V_{CC2}-0.7$		V
	$V_{IL} = 0.8$ V, $I_{OH} = -10$ mA	$V_{CC2}-2.3$	$V_{CC2}-1.8$		V
V_{OL} Low-Level Output Voltage	$V_{IH} = 2$ V, $I_{OL} = 10$ mA		0.15	0.3	V
	$V_{CC2} = 15$ V to 24V, $V_{IH} = 2$ V, $I_{OL} = 40$ mA		0.25	0.5	V
V_O Output Clamp Voltage	$V_i = 0$ V, $I_{OH} = 20$ mA			$V_{CC2}+1.5$	V
I_i Input Current at Maximum Input Voltage	$V_i = 5.5$ V			1	mA
I_{IH} High-Level Input Current	$V_i = 2.4$ V	A Inputs		40	μ A
		E Input		80	μ A
I_{IL} Low-Level Input Current	$V_i = 0.4$ V	A Inputs	-1	-1.6	mA
		E Input	-2	-3.2	mA
$I_{CC1(H)}$ Supply Current from V_{CC1} , Both Outputs High	$V_{CC1} = 5.25$ V, $V_{CC2} = 24$ V, All Inputs at 0V, No Load		2	4	mA
$I_{CC2(H)}$ Supply Current from V_{CC2} , Both Outputs High				0.5	mA
$I_{CC1(L)}$ Supply Current from V_{CC1} , Both Outputs Low	$V_{CC1} = 5.25$ V, $V_{CC2} = 24$ V, All Inputs at 5V, No Load		16	24	mA
$I_{CC2(L)}$ Supply Current from V_{CC2} , Both Outputs Low			7	11	mA
$I_{CC2(S)}$ Supply Current from V_{CC2} , Stand-by Condition	$V_{CC1} = 0$ V, $V_{CC2} = 24$ V, All Inputs at 5V, No Load			0.5	mA

Switching Characteristics ($V_{CC1} = 5$ V, $V_{CC2} = 20$ V, $T_A = 25$ °C)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{DLH} Delay Time, Low-to-High Level Output	$C_L = 390$ pF, $R_D = 10$ Ω (Figure 1)		11	20	ns	
t_{DHL} Delay Time, High-to-Low Level Output			10	18	ns	
t_{TLH} Transition Time, Low-to-High Level Output				25	40	ns
t_{THL} Transition Time, High-to-Low Level Output				21	35	ns
t_{PLH} Propagation Delay Time, Low-to-High Level Output			10	36	55	ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output			10	31	47	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

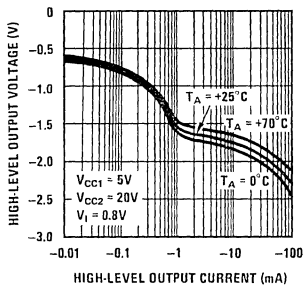
Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS75361. All typical values are for $T_A = 25$ °C and $V_{CC1} = 5$ V and $V_{CC2} = 20$ V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

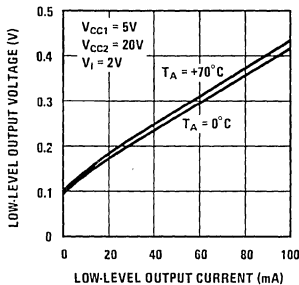
Note 4: This rating applies between the A input of either driver and the common E input.

Typical Performance Characteristics

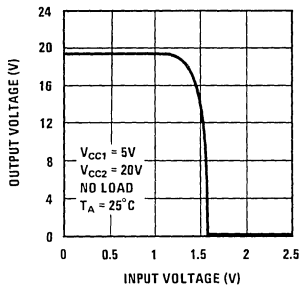
High-Level Output Voltage vs Output Current



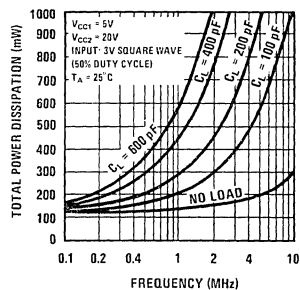
Low-Level Output Voltage vs Output Current



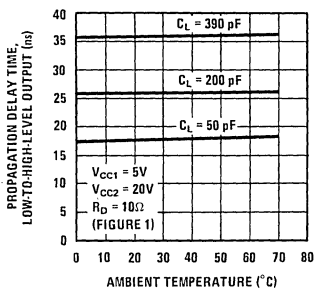
Voltage Transfer Characteristics



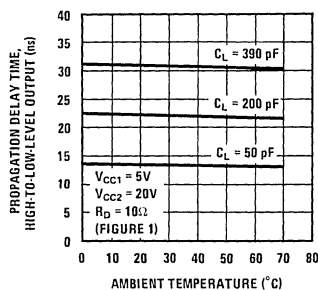
Total Dissipation (Both Drivers) vs Frequency



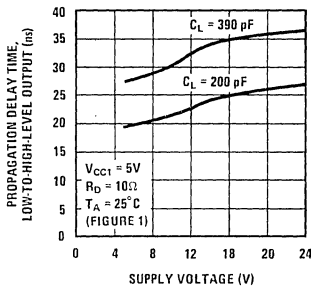
Propagation Delay Time, Low-to-High Level Output vs Ambient Temperature



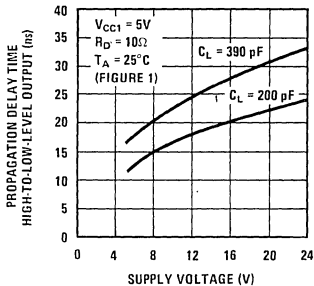
Propagation Delay Time, High-to-Low Level Output vs Ambient Temperature



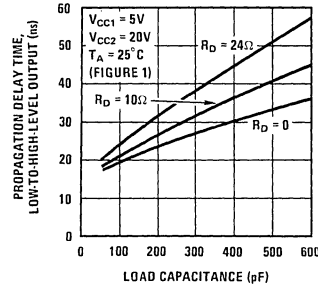
Propagation Delay Time, Low-to-High Level Output vs VCC2 Supply Voltage



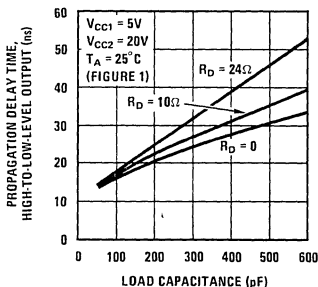
Propagation Delay Time, High-to-Low Level Output vs VCC2 Supply Voltage



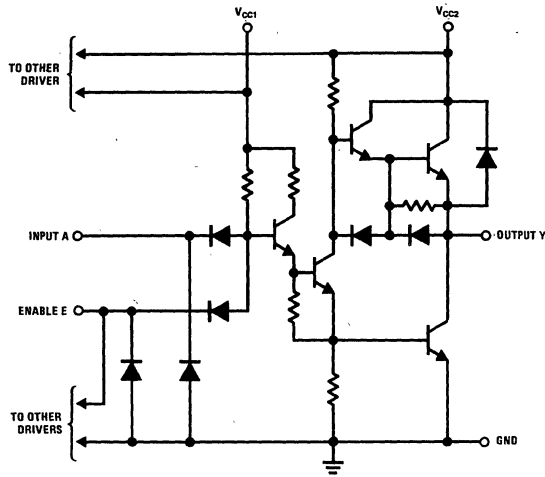
Propagation Delay Time, Low-to-High Level Output vs Load Capacitance



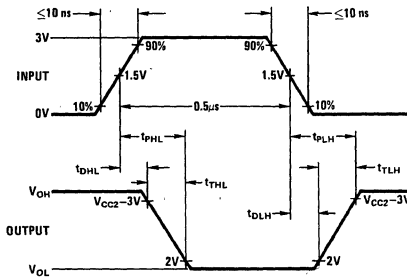
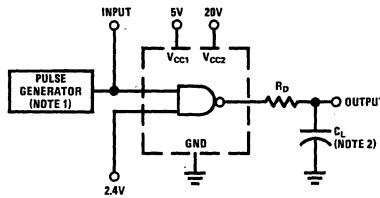
Propagation Delay Time, High-to-Low Level Output vs Load Capacitance



Schematic Diagram (1/2 shown)



AC Test Circuit and Switching Time Waveforms



Note 1: The pulse generator has the following characteristics: PRR = 1 MHz, $Z_{OUT} \approx 50\Omega$.

Note 2: C_L includes probe and jig capacitance.

FIGURE 1. Switching Times, Each Driver

Typical Applications

The fast switching speeds of this device may produce undesirable output transient overshoot because of load or wiring inductance. A small series damping resistor may be used to reduce or eliminate this output transient

overshoot. The optimum value of the damping resistor to use depends on the specific load characteristics and switching speed. A typical value would be between 10Ω and 30Ω (Figure 3).

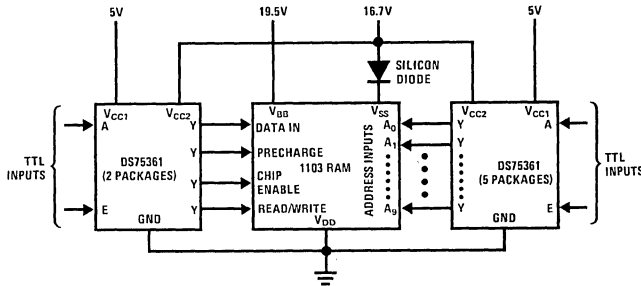
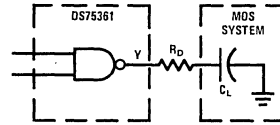


FIGURE 2. Interconnection of DS75361 Devices with 1103 RAM



Note: $R_D \approx 10\Omega$ to 30Ω (Optional).

FIGURE 3. Use of Damping Resistor to Reduce or Eliminate Output Transient Overshoot in Certain DS75361 Applications

Thermal Information

POWER DISSIPATION PRECAUTIONS

Significant power may be dissipated in the DS75361 driver when charging and discharging high-capacitance loads over a wide voltage range at high frequencies. The total dissipation curve shows the power dissipated in a typical DS75361 as a function of load capacitance and frequency. Average power dissipated by this driver can be broken into three components:

$$P_{T(AV)} = P_{DC(AV)} + P_{C(AV)} + P_{S(AV)}$$

where $P_{DC(AV)}$ is the steady-state power dissipation with the output high or low, $P_{C(AV)}$ is the power level during charging or discharging of the load capacitance, and $P_{S(AV)}$ is the power dissipation during switching between the low and high levels. None of these include energy transferred to the load and all are averaged over a full cycle.

The power components per driver channel are:

$$P_{DC(AV)} = \frac{P_L t_L + P_H t_H}{T}$$

$$P_{C(AV)} \approx C V_C^2 f$$

$$P_{S(AV)} = \frac{P_{LH} t_{LH} + P_{HL} t_{HL}}{T}$$

where the times are as defined in Figure 4.

P_L , P_H , P_{LH} , and P_{HL} are the respective instantaneous levels of power dissipation and C is load capacitance.

The DS75361 is so designed that P_S is a negligible portion of P_T in most applications. Except at very high frequencies, $t_L + t_H \gg t_{LH} + t_{HL}$ so that P_S can be

neglected. The total dissipation curve for no load demonstrates this point. The power dissipation contributions from both channels are then added together to obtain total device power.

The following example illustrates this power calculation technique. Assume both channels are operating identically with $C = 200$ pF, $f = 2$ MHz, $V_{CC1} = 5V$, $V_{CC2} = 20V$, and duty cycle = 60% outputs high ($t_H/T = 0.6$). Also, assume $V_{OH} = 19.3V$, $V_{OL} = 0.1V$, P_S is negligible, and that the current from V_{CC2} is negligible when the output is high.

On a per-channel basis using data sheet values:

$$P_{DC(AV)} = \left[(5V) \left(\frac{2 \text{ mA}}{2} \right) + (20V) \left(\frac{0 \text{ mA}}{2} \right) \right] (0.6) + \left[(5V) \left(\frac{16 \text{ mA}}{2} \right) + (20V) \left(\frac{7 \text{ mA}}{2} \right) \right] (0.4)$$

$$P_{DC(AV)} = 47 \text{ mW per channel}$$

$$P_{C(AV)} \approx (200 \text{ pF}) (19.2V)^2 (2 \text{ MHz})$$

$$P_{C(AV)} \approx 148 \text{ mW per channel}$$

For the total device dissipation of the two channels:

$$P_{T(AV)} \approx 2 (47 + 148)$$

$$P_{T(AV)} \approx 390 \text{ mW typical for total package}$$

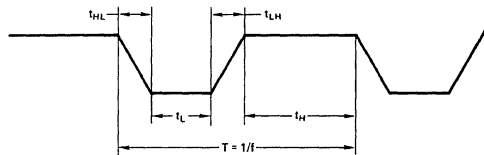


FIGURE 4. Output Voltage Waveform

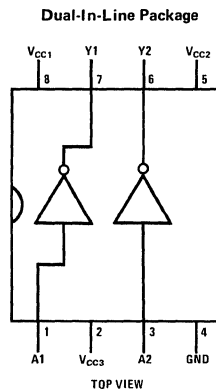
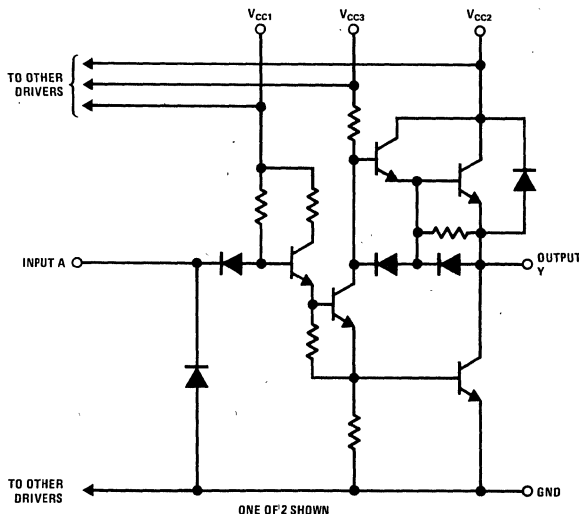
DS75362 Dual TTL-to-MOS Driver**General Description**

The DS75362 is a dual monolithic integrated TTL-to-MOS driver and interface circuit that accepts standard TTL input signals and provides high-current and high-voltage output levels suitable for driving MOS circuits. It is used to drive address, control, and timing inputs for several types of MOS RAMs including the 1103.

The DS75362 operates from the TTL 5V supply and the MOS V_{SS} and V_{BB} supplies in many applications. This device has been optimized for operation with V_{CC2} supply voltage from 16V to 20V, and with nominal V_{CC3} supply voltage from 3V to 4V higher than V_{CC2} . However, it is designed so as to be usable over a much wider range of V_{CC2} and V_{CC3} . In some applications the V_{CC3} power supply can be eliminated by connecting the V_{CC3} pin to the V_{CC2} pin.

Features

- Dual positive-logic NAND TTL-to-MOS driver
- Versatile interface circuit for use between TTL and high-current, high-voltage systems
- Capable of driving high-capacitance loads
- Compatible with many popular MOS RAMs
- V_{CC2} supply voltage variable over wide range to 24V maximum
- V_{CC3} supply voltage pin available
- V_{CC3} pin can be connected to V_{CC2} pin in some applications
- TTL compatible diode-clamped inputs
- Operates from standard bipolar and MOS supply voltages
- High-speed switching
- Transient overdrive minimizes power dissipation
- Low standby power dissipation

Schematic and Connection Diagrams

Order Number DS75362J-8 or DS75362N
See NS Package J08A or N08A

Absolute Maximum Ratings (Note 1)

Supply Voltage Range of V _{CC1}	-0.5V to 7V
Supply Voltage Range of V _{CC2}	-0.5V to 25V
Supply Voltage Range of V _{CC3}	-0.5V to 30V
Input Voltage	5.5V
Inter-Input Voltage (Note 4)	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Molded Package	1022 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate molded package 8.2 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC1})	4.75	5.25	V
Supply Voltage (V _{CC2})	4.75	24	V
Supply Voltage (V _{CC3})	V _{CC2}	28	V
Voltage Difference Between Supply Voltages: V _{CC3} -V _{CC2}	0	10	V
Operating Ambient Temperature Range (T _A)	0	70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH}	High-Level Input Voltage	2			V	
V _{IL}	Low-Level Input Voltage			0.8	V	
V _I	Input Clamp Voltage	I _I = -12 mA		-1.5	V	
V _{OH}	High-Level Output Voltage	V _{CC3} = V _{CC2} +3V, V _{IL} = 0.8V, I _{OH} = -100μA	V _{CC2} -0.3	V _{CC2} -0.1	V	
		V _{CC3} = V _{CC2} +3V, V _{IL} = 0.8V, I _{OH} = -10 mA	V _{CC2} -1.2	V _{CC2} -0.9	V	
		V _{CC3} = V _{CC2} , V _{IL} = 0.8V, I _{OH} = -50μA	V _{CC2} -1	V _{CC2} -0.7	V	
		V _{CC3} = V _{CC2} , V _{IL} = 0.8V, I _{OH} = -10 mA	V _{CC2} -2.3	V _{CC2} -1.8	V	
V _{OL}	Low-Level Output Voltage	V _{IH} = 2V, I _{OL} = 10 mA		0.15	0.3	V
		V _{CC3} = 15V to 28V, V _{IH} = 2V, I _{OL} = 40 mA		0.25	0.5	V
V _O	Output Clamp Voltage	V _I = 0V, I _{OH} = 20 mA		V _{CC2} +1.5	V	
I _I	Input Current at Maximum Input Voltage	V _I = 5.5V		1	mA	
I _{IH}	High-Level Input Current	V _I = 2.4V		40	μA	
I _{IL}	Low-Level Input Current	V _I = 0.4V	-1	-1.6	mA	
I _{CC1(H)}	Supply Current from V _{CC1} , All Outputs High	V _{CC1} = 5.25V, V _{CC2} = 24V, V _{CC3} = 28V, All Inputs at 0V, No Load	2	4	mA	
I _{CC2(H)}	Supply Current from V _{CC2} , All Outputs High		-1.1	+0.25	mA	
I _{CC3(H)}	Supply Current from V _{CC3} , All Outputs High		-1.1	-1.6	mA	
I _{CC1(L)}	Supply Current from V _{CC1} , All Outputs Low	V _{CC1} = 5.25V, V _{CC2} = 24V, V _{CC3} = 28V, All Inputs at 5V, No Load	1.1	1.8	mA	
I _{CC2(L)}	Supply Current from V _{CC2} , All Outputs Low		15	23.5	mA	
I _{CC3(L)}	Supply Current from V _{CC3} , All Outputs Low		8	12.5	mA	
I _{CC2(H)}	Supply Current from V _{CC2} , All Outputs High	V _{CC1} = 5.25V, V _{CC2} = 24V, V _{CC3} = 24V, All Inputs at 0V, No Load		0.25	mA	
I _{CC3(H)}	Supply Current from V _{CC3} , All Outputs High			0.5	mA	
I _{CC2(S)}	Supply Current from V _{CC2} , Stand-by Condition	V _{CC1} = 0V, V _{CC2} = 24V, V _{CC3} = 24V, All Inputs at 5V, No Load		0.25	mA	
I _{CC3(S)}	Supply Current from V _{CC3} , Stand-by Condition			0.5	mA	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS75362. All typical values are for T_A = 25°C and V_{CC1} = 5V and V_{CC2} = 20V and V_{CC3} = 24V.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

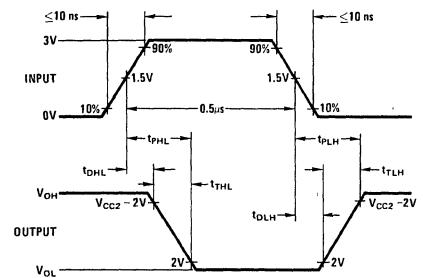
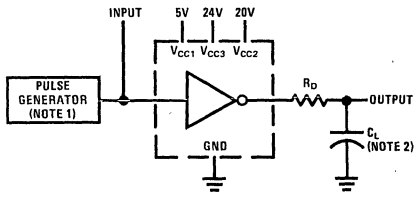
Note 4: This rating applies between any two inputs of any one of the gates.

Switching Characteristics

($V_{CC1} = 5V, V_{CC2} = 20V, V_{CC3} = 24V, T_A = 25^\circ C$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{DLH} Delay Time, Low-to-High Level Output	$C_L = 200\text{ pF},$ $R_D = 24\Omega,$ <i>(Figure 1)</i>		11	20	ns	
t_{DHL} Delay Time, High-to-Low Level Output			10	18	ns	
t_{TLH} Transition Time, Low-to-High Level Output				20	33	ns
t_{THL} Transition Time, High-to-Low Level Output				20	33	ns
t_{PLH} Propagation Delay Time, Low-to-High Level Output			10	31	48	ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output			10	30	46	ns

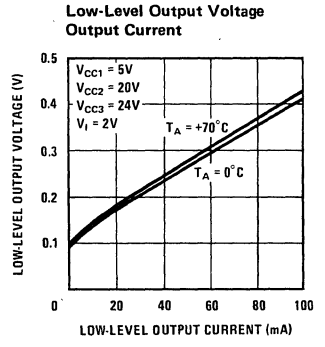
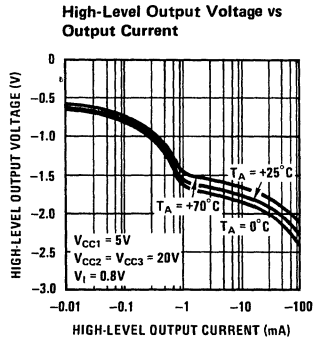
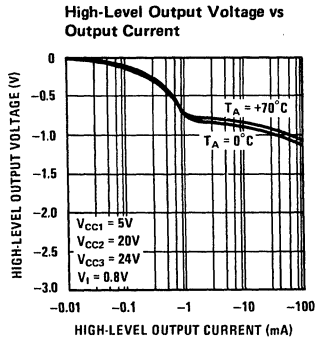
AC Test Circuit and Switching Time Waveforms



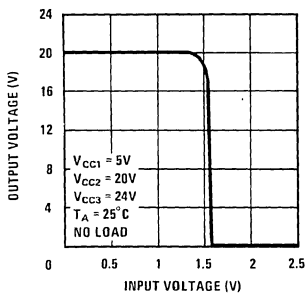
Note 1: The pulse generator has the following characteristics: PRR = 1 MHz, $Z_{OUT} \approx 50\Omega$.
 Note 2: C_L includes probe and jig capacitance.

FIGURE 1. Switching Times, Each Driver

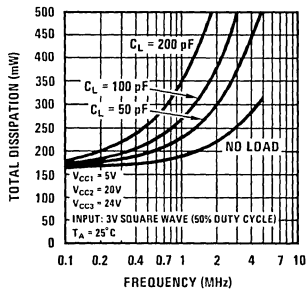
Typical Performance Characteristics



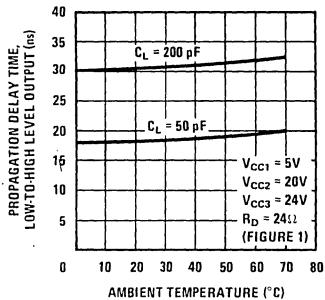
Voltage Transfer Characteristics



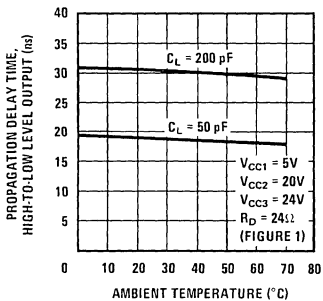
Total Dissipation (Two Drivers) vs Frequency



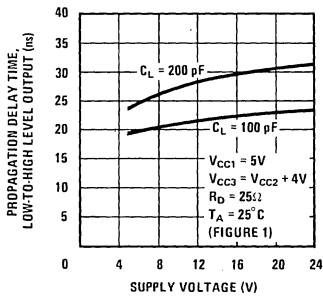
Propagation Delay Time, Low-to-High Level Output vs Ambient Temperature



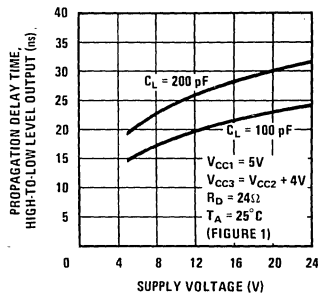
Propagation Delay Time, High-to-Low Level Output vs Ambient Temperature



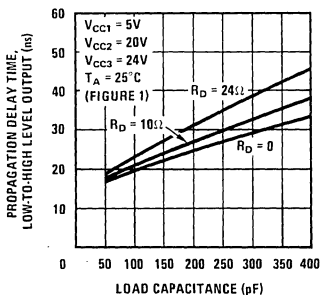
Propagation Delay Time, Low-to-High Level Output vs VCC2 Supply Voltage



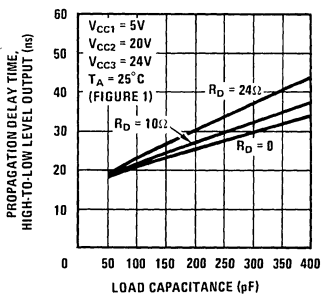
Propagation Delay Time, High-to-Low Level Output vs VCC2 Supply Voltage



Propagation Delay Time, Low-to-High Level Output vs Load Capacitance

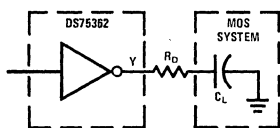


Propagation Delay Time, High-to-Low Level Output vs Load Capacitance



Typical Application

The fast switching speeds of this device may produce undesirable output transient overshoot because of load or wiring inductance. A small series damping resistor may be used to reduce or eliminate this output transient overshoot. The optimum value of the damping resistor depends on the specific load characteristics and switching speed. A typical value would be between 10Ω and 30Ω (Figure 2).



Note: $R_D \approx 10\Omega$ to 30Ω (Optional).

FIGURE 2. Use of Damping Resistor to Reduce or Eliminate Output Transient Overshoot In Certain DS75362 Applications.

Thermal Information

POWER DISSIPATION PRECAUTIONS

Significant power may be dissipated in the DS75362 driver when charging and discharging high-capacitance loads over a wide voltage range at high frequencies. The total dissipation curve shows the power dissipated in a typical DS75362 as a function of load capacitance and frequency. Average power dissipation by this driver can be broken into three components:

$$P_{T(AV)} = P_{DC(AV)} + P_{C(AV)} + P_{S(AV)}$$

where $P_{DC(AV)}$ is the steady-state power dissipation with the output high or low, $P_{C(AV)}$ is the power level during charging or discharging of the load capacitance, and $P_{S(AV)}$ is the power dissipation during switching between the low and high levels. None of these include energy transferred to the load and all are averaged over a full cycle.

The power components per driver channel are:

$$P_{DC(AV)} = \frac{P_L t_L + P_H t_H}{T}$$

$$P_{C(AV)} \approx C V_C^2 f$$

$$P_{S(AV)} = \frac{P_{LH} t_{LH} + P_{HL} t_{HL}}{T}$$

where the times are as defined in Figure 3.

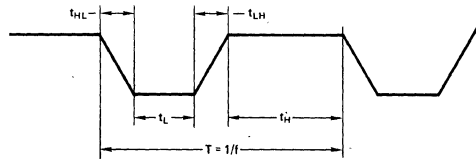


FIGURE 3. Output Voltage Waveform

P_L , P_H , P_{LH} , and P_{HL} are the respective instantaneous levels of power dissipation and C is load capacitance.

The DS75362 is so designed that P_S is a negligible portion of P_T in most applications. Except at very high frequencies, $t_L + t_H \gg t_{LH} + t_{HL}$ so that P_S can be neglected. The total dissipation curve for no load demonstrates this point. The power dissipation contributions from two channels are then added together to obtain total device power.

The following example illustrates this power calculation technique. Assume two channels are operating identically with $C = 100$ pF, $f = 2$ MHz, $V_{CC1} = 5V$, $V_{CC2} = 20V$, $V_{CC3} = 24V$ and duty cycle = 60% outputs high ($t_H/T = 0.6$). Also, assume $V_{OH} = 20V$, $V_{OL} = 0.1V$, P_S is negligible, and that the current from V_{CC2} is negligible when the output is low.

On a per-channel basis using data sheet values:

$$P_{DC(AV)} = \left[(5V) \left(\frac{4 \text{ mA}}{4} \right) + (20V) \left(\frac{-2.2 \text{ mA}}{4} \right) + (24V) \right.$$

$$\left. \left(\frac{2.2 \text{ mA}}{4} \right) \right] (0.6) + \left[(5V) \left(\frac{31 \text{ mA}}{4} \right) + \right.$$

$$\left. (20V) \left(\frac{0 \text{ mA}}{4} \right) + (24V) \left(\frac{16 \text{ mA}}{4} \right) \right] (0.4)$$

$$P_{DC(AV)} = 58 \text{ mW per channel}$$

$$P_{C(AV)} \approx (100 \text{ pF}) (19.9V)^2 (2 \text{ MHz})$$

$$P_{C(AV)} \approx 79 \text{ mW per channel.}$$

For the total device dissipation of the two channels

$$P_{T(AV)} \approx 2 (58 + 79)$$

$$P_{T(AV)} \approx 274 \text{ mW typical for total package.}$$

DS75365 Quad TTL-to-MOS Driver

General Description

The DS75365 is a quad monolithic integrated TTL-to-MOS driver and interface circuit that accepts standard TTL input signals and provides high-current and high-voltage output levels suitable for driving MOS circuits. It is used to drive address, control, and timing inputs for several types of MOS RAMs including the 1103.

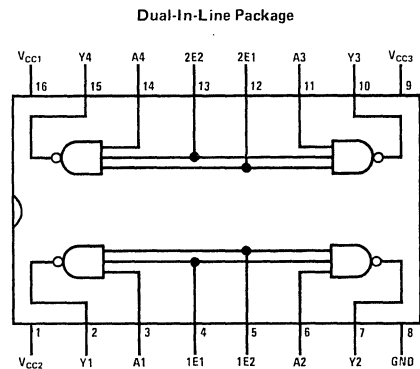
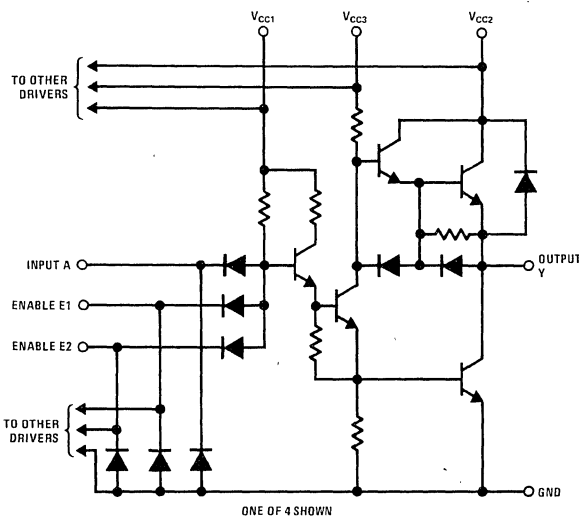
The DS75365 operates from the TTL 5V supply and the MOS V_{SS} and V_{BB} supplies in many applications. This device has been optimized for operation with V_{CC2} supply voltage from 16V to 20V, and with nominal V_{CC3} supply voltage from 3V to 4V higher than V_{CC2} . However, it is designed so as to be usable over a much wider range of V_{CC2} and V_{CC3} . In some applications the V_{CC3} power supply can be eliminated by connecting the V_{CC3} pin to the V_{CC2} pin.

- Capable of driving high-capacitance loads
- Compatible with many popular MOS RAMs
- Interchangeable with Intel 3207
- V_{CC2} supply voltage variable over wide range to 24V maximum
- V_{CC3} supply voltage pin available
- V_{CC3} pin can be connected to V_{CC2} pin in some applications
- TTL compatible diode-clamped inputs
- Operates from standard bipolar and MOS supply voltages
- Two common enable inputs per gate-pair
- High-speed switching
- Transient overdrive minimizes power dissipation
- Low standby power dissipation

Features

- Quad positive-logic NAND TTL-to-MOS driver
- Versatile interface circuit for use between TTL and high-current, high-voltage systems

Schematic and Connection Diagrams



TOP VIEW

Positive Logic: $Y = \overline{A \cdot E1 \cdot E2}$

Order Number **DS75365J**
or **DS75365N**
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

Supply Voltage Range of V _{CC1}	-0.5V to 7V
Supply Voltage Range of V _{CC2}	-0.5V to 25V
Supply Voltage Range of V _{CC3}	-0.5V to 30V
Input Voltage	5.5V
Inter-Input Voltage (Note 4)	5.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC1})	4.75	5.25	V
Supply Voltage (V _{CC2})	4.75	24	V
Supply Voltage (V _{CC3})	V _{CC2}	28	V
Voltage Difference Between Supply Voltages: V _{CC3} -V _{CC2}	0	10	V
Operating Ambient Temperature Range (T _A)	0	70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS	
V _{IH}	High-Level Input Voltage		2			V	
V _{IL}	Low-Level Input Voltage				0.8	V	
V _I	Input Clamp Voltage		I _I = -12 mA		-1.5	V	
V _{OH}	High-Level Output Voltage	V _{CC3} = V _{CC2} +3V, V _{IL} = 0.8V, I _{OH} = -100μA	V _{CC2} -0.3	V _{CC2} -0.1		V	
		V _{CC3} = V _{CC2} +3V, V _{IL} = 0.8V, I _{OH} = -10 mA	V _{CC2} -1.2	V _{CC2} -0.9		V	
		V _{CC3} = V _{CC2} , V _{IL} = 0.8V, I _{OH} = -50μA	V _{CC2} -1	V _{CC2} -0.7		V	
		V _{CC3} = V _{CC2} , V _{IL} = 0.8V, I _{OH} = -10 mA	V _{CC2} -2.3	V _{CC2} -1.8		V	
V _{OL}	Low-Level Output Voltage	V _{IH} = 2V, I _{OL} = 10 mA		0.15	0.3	V	
		V _{CC3} = 15V to 28V, V _{IH} = 2V, I _{OL} = 40 mA		0.25	0.5	V	
V _O	Output Clamp Voltage				V _{CC2} +1.5	V	
I _I	Input Current at Maximum Input Voltage		V _I = 5.5V		1	mA	
I _{IH}	High-Level Input Current	V _I = 2.4V	A Inputs		40	μA	
			E1 and E2 Inputs		80	μA	
I _{IL}	Low-Level Input Current	V _I = 0.4V	A Inputs		-1	-1.6	mA
			E1 and E2 Inputs		-2	-3.2	mA
I _{CC1(H)}	Supply Current from V _{CC1} , All Outputs High	V _{CC1} = 5.25V, V _{CC2} = 24V, V _{CC3} = 28V, All Inputs at 0V, No Load		4	8	mA	
I _{CC2(H)}	Supply Current from V _{CC2} , All Outputs High		-2.2	+0.25	mA		
			-2.2	-3.2	mA		
I _{CC3(H)}	Supply Current from V _{CC3} , All Outputs High		2.2	3.5	mA		
I _{CC1(L)}	Supply Current from V _{CC1} , All Outputs Low		31	47	mA		
I _{CC2(L)}	Supply Current from V _{CC2} , All Outputs Low			3	mA		
I _{CC3(L)}	Supply Current from V _{CC3} , All Outputs Low	16	25	mA			
I _{CC2(H)}	Supply Current from V _{CC2} , All Outputs High	V _{CC1} = 5.25V, V _{CC2} = 24V, V _{CC3} = 24V, All Inputs at 0V, No Load		0.25	mA		
I _{CC3(H)}	Supply Current from V _{CC3} , All Outputs High			0.5	mA		
I _{CC2(S)}	Supply Current from V _{CC2} , Stand-by Condition	V _{CC1} = 0V, V _{CC2} = 24V, V _{CC3} = 24V, All Inputs at 5V, No Load		0.25	mA		
I _{CC3(S)}	Supply Current from V _{CC3} , Stand-by Condition			0.5	mA		

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DS75365. All typical values are for T_A = 25°C and V_{CC1} = 5V and V_{CC2} = 20V and V_{CC3} = 24V.

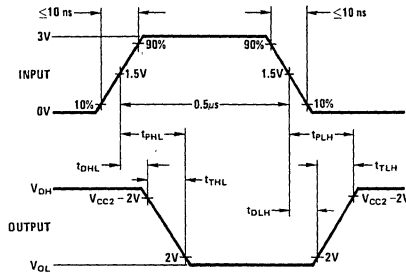
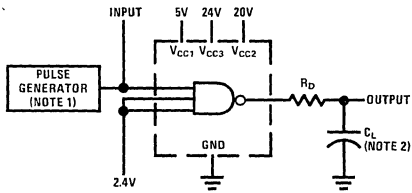
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: This rating applies between any two inputs of any one of the gates.

Switching Characteristics ($V_{CC1} = 5V, V_{CC2} = 20V, V_{CC3} = 24V, T_A = 25^\circ C$)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
t_{DLH} Delay Time, Low-to-High Level Output	$C_L = 200 \text{ pF},$ $R_D = 24\Omega,$ <i>(Figure 1)</i>		11	20	ns	
t_{DHL} Delay Time, High-to-Low Level Output			10	18	ns	
t_{TLH} Transition Time, Low-to-High Level Output			20	33	ns	
t_{THL} Transition Time, High-to-Low Level Output			20	33	ns	
t_{PLH} Propagation Delay Time, Low-to-High Level Output			10	31	48	ns
t_{PHL} Propagation Delay Time, High-to-Low Level Output			10	30	46	ns

AC Test Circuit and Switching Time Waveforms

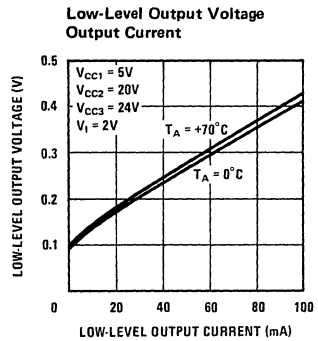
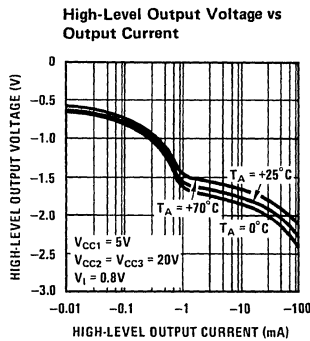
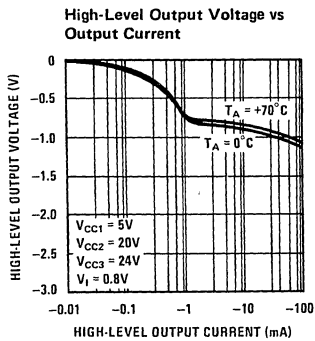


Note 1: The pulse generator has the following characteristics: PRR = 1 MHz, $Z_{OUT} = 50\Omega$.
 Note 2: C_L includes probe and jig capacitance.

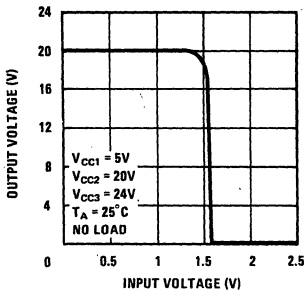
FIGURE 1. Switching Times, Each Driver

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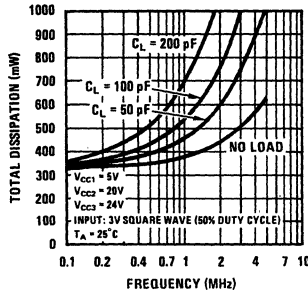
Typical Performance Characteristics



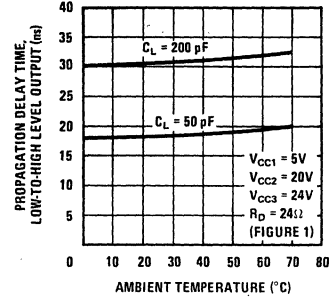
Voltage Transfer Characteristics



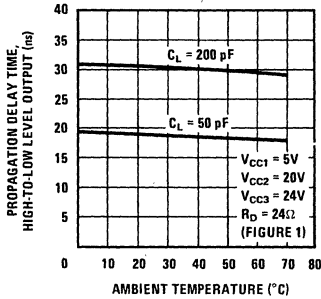
Total Dissipation (All Four Drivers) vs Frequency



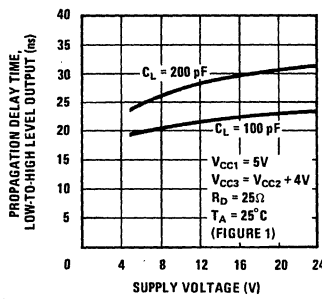
Propagation Delay Time, Low-to-High Level Output vs Ambient Temperature



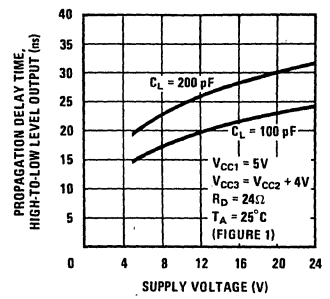
Propagation Delay Time, High-to-Low Level Output vs Ambient Temperature



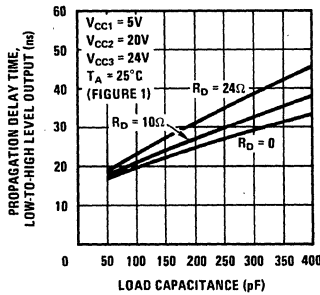
Propagation Delay Time, Low-to-High Level Output vs VCC2 Supply Voltage



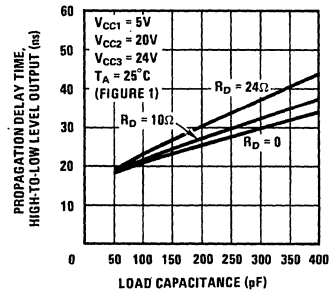
Propagation Delay Time, High-to-Low Level Output vs VCC2 Supply Voltage



Propagation Delay Time, Low-to-High Level Output vs Load Capacitance



Propagation Delay Time, High-to-Low Level Output vs Load Capacitance



Typical Applications

The fast switching speeds of this device may produce undesirable output transient overshoot because of load or wiring inductance. A small series damping resistor may be used to reduce or eliminate this output transient

overshoot. The optimum value of the damping resistor depends on the specific load characteristics and switching speed. A typical value would be between 10Ω and 30Ω (Figure 3).

Typical Applications (Continued)

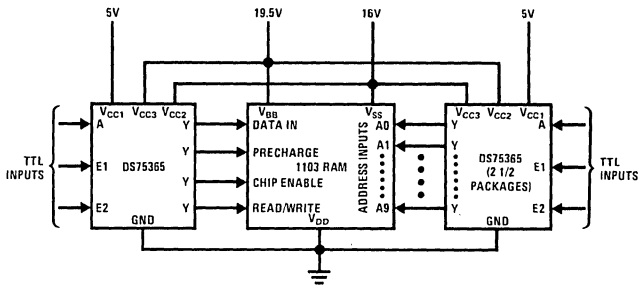
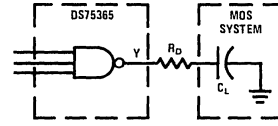


FIGURE 2. Interconnection of DS75365 Devices with 1103-Type Silicon-Gate MOS RAM



Note: $R_D \approx 10\Omega$ to 30Ω (Optional).

FIGURE 3. Use of Damping Resistor to Reduce or Eliminate Output Transient Overshoot in Certain DS75365 Applications

Thermal Information

POWER DISSIPATION PRECAUTIONS

Significant power may be dissipated in the DS75365 driver when charging and discharging high-capacitance loads over a wide voltage range at high frequencies. The total dissipation curve shows the power dissipated in a typical DS75365 as a function of load capacitance and frequency. Average power dissipation by this driver can be broken into three components:

$$P_{T(AV)} = P_{DC(AV)} + P_{C(AV)} + P_{S(AV)}$$

where $P_{DC(AV)}$ is the steady-state power dissipation with the output high or low, $P_{C(AV)}$ is the power level during charging or discharging of the load capacitance, and $P_{S(AV)}$ is the power dissipation during switching between the low and high levels. None of these include energy transferred to the load and all are averaged over a full cycle.

The power components per driver channel are:

$$P_{DC(AV)} = \frac{P_L t_L + P_H t_H}{T}$$

$$P_{C(AV)} \approx C V_C^2 f$$

$$P_{S(AV)} = \frac{P_{LH} t_{LH} + P_{HL} t_{HL}}{T}$$

where the times are as defined in Figure 4.

P_L , P_H , P_{LH} , and P_{HL} are the respective instantaneous levels of power dissipation and C is load capacitance.

The DS75365 is so designed that P_S is a negligible portion of P_T in most applications. Except at very high frequencies, $t_L + t_H \gg t_{LH} + t_{HL}$ so that P_S can be

neglected. The total dissipation curve for no load demonstrates this point. The power dissipation contributions from all four channels are then added together to obtain total device power.

The following example illustrates this power calculation technique. Assume all four channels are operating identically with $C = 100$ pF, $f = 2$ MHz, $V_{CC1} = 5$ V, $V_{CC2} = 20$ V, $V_{CC3} = 24$ V and duty cycle = 60% outputs high ($t_H/T = 0.6$). Also, assume $V_{OH} = 20$ V, $V_{OL} = 0.1$ V, P_S is negligible, and that the current from V_{CC2} is negligible when the output is low.

On a per-channel basis using data sheet values:

$$P_{DC(AV)} = \left[(5V) \left(\frac{4 \text{ mA}}{4} \right) + (20V) \left(\frac{-2.2 \text{ mA}}{4} \right) + (24V) \left(\frac{2.2 \text{ mA}}{4} \right) \right] (0.6) + \left[(5V) \left(\frac{31 \text{ mA}}{4} \right) + (20V) \left(\frac{0 \text{ mA}}{4} \right) + (24V) \left(\frac{16 \text{ mA}}{4} \right) \right] (0.4)$$

$$P_{DC(AV)} = 58 \text{ mW per channel}$$

$$P_{C(AV)} \approx (100 \text{ pF}) (19.9V)^2 (2 \text{ MHz})$$

$$P_{C(AV)} \approx 79 \text{ mW per channel.}$$

For the total device dissipation of the four channels:

$$P_{T(AV)} \approx 4 (58 + 79)$$

$$P_{T(AV)} \approx 548 \text{ mW typical for total package.}$$

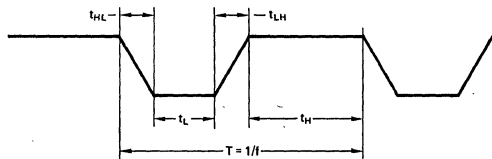


FIGURE 4. Output Voltage Waveform

Applying Modern Clock Drivers to MOS Memories

National Semiconductor
Application Note 76
B. Siegel
M. Scott
October 1975



INTRODUCTION

MOS memories present unique system and circuit challenges to the engineer since they require precise timing of input wave forms. Since these inputs present large capacitive loads to drive circuits, it is often that timing problems are not discovered until an entire system is constructed. This paper covers the practical aspects of using modern clock drivers in MOS memory systems. Information includes selection of packages and heat sinks, power dissipation, rise and fall time considerations, power supply decoupling, system clock line ringing and crosstalk, input coupling techniques, and example calculations. Applications covered include driving various types shift registers and RAM's (Random Access Memories) using logical control as well as other techniques to assure correct non-overlap of timing waveforms.

Although the information given is generally applicable to any type of driver, monolithic integrated circuit drivers, the DS0025, DS0026 and DS0056 are selected as examples because of their low cost.

The DS0025 was the first monolithic clock driver. It is intended for applications up to one megacycle where low cost is of prime concern. Table I illustrates its performance while Appendix I describes its circuit operation. Its monolithic, rather than hybrid or module construction, was made possible by a new high voltage-gold doped process utilizing a collector sinker to minimize $V_{CE SAT}$.

The DS0026 is a high speed, low cost, monolithic clock driver intended for applications above one megacycle. Table II illustrates its performance characteristics while its unique circuit design is presented in Appendix II. The DS0056 is a variation of the DS0026 circuit which allows the system designer to modify the output performance of the circuit. The DS0056 can be connected (using a second power supply) to increase the positive output voltage level and reduce the effect of cross coupling capacitance between the clock lines in the system. Of course the above are just examples of the many different types that are commercially available. Other National Semiconductor MOS interface circuits are listed in Appendix III.

The following section will hopefully allow the design engineer to select and apply the best circuit to his particular application while avoiding common system problems.

PRACTICAL ASPECTS OF USING MOS CLOCK DRIVERS

Package and Heat Sink Selection

Package type should be selected on power handling capability, standard size, ease of handling, availability of sockets, ease or type of heat sinking required, reliability and cost. Power handling capability for various packages is illustrated in Table III. The following guidelines are recommended:

TABLE I. DS0025 Characteristics

PARAMETER	CONDITIONS ($V^+ - V^- = 17V$)	VALUE	UNITS
t_{ON}		15	ns
t_{OFF}	$C_{IN} = 0.0022\mu F, R_{IN} = 0\Omega$	30	ns
t_r	$C_L = 0.0001\mu F, R_O = 50\Omega$	25	ns
t_f		150	ns
Positive Output Voltage Swing	$V_{IN} - V^- = 0V, I_{OUT} = -1mA$	$V^+ - 0.7$	V
Negative Output Voltage Swing	$I_{IN} = 10mA, I_{OUT} = 1mA$	$V^- + 1.0$	V
On Supply Current (V^+)	$I_{IN} = 10mA$	17	mA

TABLE II. DS0026 Characteristics

PARAMETER	CONDITIONS ($V^+ - V^- = 17V$)	VALUE	UNITS
t_{ON}		7.5	ns
t_{OFF}	$C_{IN} = 0.001\mu F, R_{IN} = 0\Omega$	7.5	ns
t_r	$R_O = 50\Omega, C_L = 1000 pF$	25	ns
t_f		25	ns
Positive Output Voltage Swing	$V_{IN} - V^- = 0V, I_{OUT} = -1mA$	$V^+ - 0.7$	V
Negative Output Voltage Swing	$I_{IN} = 10mA, I_{OUT} = 1mA$	$V^- + 0.5$	V
On Supply Current (V^+)	$I_{IN} = 10mA$	28	mA

The TO-5 ("H") package is rated at 750 mW still air (derate at 200°C/W above 25°C) soldered to PC board. This popular cavity package is recommended for small systems. Low cost (about 10 cents) clip-on heat sink increases driving capability by 50%.

The 8-pin ("N") molded mini-DIP is rated at 600 mW still air (derate at 90°C/W above 25°C) soldered to PC board (derate at 1.39W). Constructed with a special copper lead frame, this package is recommended for medium size commercial systems particularly where automatic insertion is used. (Please note for prototype work, that this package is only rated at 600 mW when mounted in a socket and not one watt until it is soldered down.)

To TO-8 ("G") package is rated at 1.5W still air (derate at 100°C/W above 25°C) and 2.3W with clip-on heat sink (Wakefield type 215-1.9 or equivalent-derate at 15 mW/°C). Selected for its power handling capability and moderate cost, this hermetic package will drive very large systems at the lowest cost per bit.

Additional information is given in the section of this data book on Maximum Power Dissipation (page 2).

Power Dissipation Considerations

The amount of registers that can be driven by a given clock driver is usually limited first by internal power dissipation. There are four factors:

1. Package and heat sink selection
2. Average dc power, P_{DC}
3. Average ac power, P_{AC}
4. Numbers of drivers per package, n

From the package heat sink, and maximum ambient temperature one can determine P_{MAX} , which is the maximum internal power a device can handle and still operate reliably. The total average power dissipated in a driver is the sum of dc power and ac power in each driver times the number of drivers. The total of which must be less than the package power rating.

$$P_{DISS} = n \times (P_{AC} + P_{DC}) \leq P_{MAX} \quad (1)$$

Average dc power has three components: input power, power in the "OFF" state (MOS logic "0") and power in the "ON" state (MOS logic "1").

$$P_{DC} = P_{IN} + P_{OFF} + P_{ON} \quad (2)$$

For most types of clock drivers, the first two terms are negligible (less than 10 mW) and may be ignored.

Thus:

$$P_{DC} \cong P_{ON} = \frac{(V^+ - V^-)^2}{R_{eq}} \times (DC)$$

where:

$V^+ - V^-$ = Total voltage across the driver

R_{eq} = Equivalent device resistance in the "ON" state

$$= V^+ - V^- / I_{S(ON)} \quad (3)$$

DC = Duty Cycle

$$= \frac{\text{"ON" Time}}{\text{"ON" Time} + \text{"OFF" Time}}$$

For the DS0025, R_{eq} is typically 1 k Ω while R_{eq} is typically 600 Ω for the DS0026. Graphical solutions for P_{DC} appear in Figure 1. For example if $V^+ = +5V$, $V^- = -12V$, $R_{eq} = 500 \Omega$, and DC = 25%, then $P_{DC} = 145$ mW. However, if the duty cycle was only 5%, $P_{DC} = 29$ mW. Thus to maximize the number of registers that can be driven by a given clock driver as well as minimizing average system power, the minimum allowable clock pulse width should be used for the particular type of MOS register.

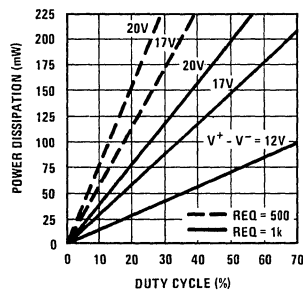


FIGURE 1. P_{DC} vs Duty Cycle

In addition to P_{DC} , the power driving a capacitive load is given approximately by:

$$P_{AC} = (V^+ - V^-)^2 \times f \times C_L \quad (4)$$

where:

f = Operating frequency

C_L = Load capacitance

Graphical solutions for P_{AC} are illustrated in Figure 2. Thus, any type of clock driver will dissipate internally 290 mW per MHz per thousand pF of load. At 5 MHz, this would be 1.5W for a 1000 pF load. For long shift register applications, the driver with the highest package power rating will drive the largest number of bits.

Combining equations (1), (2), (3) and (4) yields a criterion for the maximum load capacitance which can be driven by a given driver:

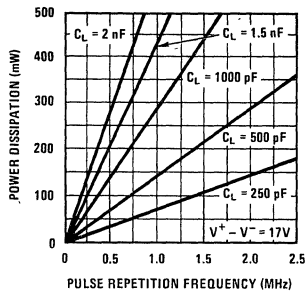


FIGURE 2. P_{AC} vs PRF

$$C_L \leq \frac{1}{f} \left[\frac{P_{MAX}}{n(V^+ - V^-)^2} - \frac{(DC)}{Req} \right] \quad (5)$$

As an example, the DS0025CN can dissipate 890 mW at $T_A = 70^\circ\text{C}$ when soldered to a printed circuit board. Req is approximately equal to 1k. For $V^+ = 5\text{V}$, $V^- = -12\text{V}$, $f = 1\text{ MHz}$, and $dc = 20\%$, C_L is:

$$C_L \leq \frac{1}{10^6} \left[\frac{(890 \times 10^{-3})}{(2)(17)^2} - \frac{0.2}{1 \times 10^3} \right]$$

$$C_L \leq 1340 \text{ pF (each driver)}$$

A typical application might involve driving an MM5013 triple 64-bit shift register with the DS0025. Using the conditions above and the clock line capacitance of the MM5013 of 60 pF, a single DS0025 can drive 1340 pF/60 pF, or 00 MM5013's.

In summary, the maximum capacitive load that any clock driver can drive is determined by package type and rating, heat sink technique, maximum system ambient temperature, ac power (which depends on frequency, voltage across the device, and capacitive load) and dc power (which is principally determined by duty cycle).

Rise and Fall Time Considerations

In general rise and fall times are determined by (a) clock driver design, (b) reflected effects of heavy external load, and (c) peak transient current available. Details of these are included in Appendixes I and II. *Figures A1-3, A1-4, A11-2 and A11-3* illustrate performance under various operating conditions. Under light loads, performance is determined by internal design of the driver; for moderate loads, by load C_L being reflected (usually as $C_{L/\beta}$) into the driver, and for large loads by peak output current where:

$$\frac{\Delta V}{\Delta T} = \frac{I_{OUT PEAK}}{C_L}$$

Logic rise and fall times must be known in order to assure non-overlap of system timing.

Note the definition of rise and fall times in this application note follow the convention that rise time is the transition from logic "0" to logic "1" levels and vice versa for fall times. Since MOS logic is inverted from normal TTL, "rise time" as used in this note is "voltage fall" and "fall time" is "voltage rise."

Power Supply Decoupling

Although power supply decoupling is a wide spread and accepted practice, the question often arises as to how much and how often. Our own experience indicates that each clock driver should have at least 0.1 μF decoupling to ground at the V^+ and V^- supply leads. Capacitors should be located as close as is physically possible to each driver. Capacitors should be non-inductive ceramic discs. This decoupling is necessary because currents in the order of 0.5 to 1.5 amperes flow during logic transitions.

There is a high current transient (as high as 1.5A) during the output transition from high to low through the V^- lead. If the external interconnecting wire from the driving circuit to the V^- lead is electrically long, or has significant dc resistance the current transient will appear as negative feedback and subtract from the switching response. To minimize this effect, short interconnecting wires are necessary and high frequency power supply decoupling capacitors are required if V^- is different from the ground of the driving circuit.

Clock Line Overshoot and Cross Talk

Overshoot: The output waveform of a clock driver can, and often does, overshoot. It is particularly evident on faster drivers. The overshoot is due to the finite inductance of the clock lines. Since most MOS registers require that clock signals not exceed V_{SS} , some method must be found in large systems to eliminate overshoot. A straightforward approach is shown in *Figure 3*. In this instance,

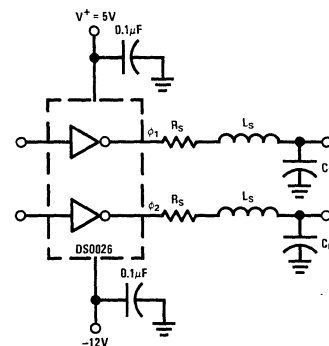


FIGURE 3. Use of Damping Resistor to Eliminate Clock Overshoot

a small damping resistor is inserted between the output of the clock driver and the load. The critical value for R_S is given by:

$$R_S = 2 \sqrt{\frac{L_S}{C_L}} \quad (6)$$

In practice, analytical determination of the value for R_S is rather difficult. However, R_S is readily determined empirically, and typical values range in value between 10 and 50Ω.

Use of the damping resistor has the added benefit of essentially unloading the clock driver; hence a greater number of loads may often be driven by a given driver. In the limit, however, the maximum value that may be used for R_S will be determined by the maximum allowable rise and fall time needed to assure proper operation of the MOS register. In short:

$$t_{r(MAX)} = t_{f(MAX)} \leq 2.2 R_S C_L \quad (7)$$

One last word of caution with regard to use of a damping resistor should be mentioned. The power dissipated in R_S can approach $(V^+ - V^-)^2 f C_L$ and accordingly the resistor wattage rating may be in excess of 1W. There are, obviously, applications where degradation of t_r and t_f by use of damping resistors cannot be tolerated. Figure 4 shows a practical circuit which will limit overshoot to a diode drop. The clamp network should physically be located in the center of the distributed load in order to minimize inductance between the clamp and registers.

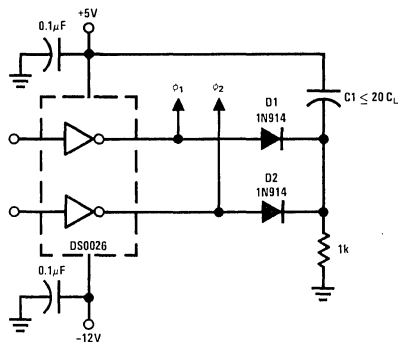


FIGURE 4. Use of High Speed Clamp to Limit Clock Overshoot

Cross Talk: Voltage spikes from ϕ_1 may be transmitted to ϕ_2 (and vice versa) during the transition of ϕ_1 to MOS logic "1." The spike is due to mutual capacitance between clock lines and is, in general, aggravated by long clock lines when numerous registers are being driven. Figure 5 illustrates the problem.

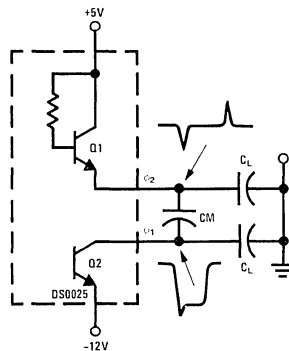


FIGURE 5. Clock Line Cross Talk

The negative going transition of ϕ_1 (to MOS logic "1") is capacitively coupled via C_M to ϕ_2 . Obviously, the larger C_M is, the larger the spike. Prior to ϕ_1 's transition, Q1 is "OFF" since only μA are drawn from the device.

The DS0056 connected as shown in Figure 6 will minimize the effect of cross talk. The external resistors to the higher power supply pull the base of a Q1 up to a higher level and forward bias the collector base junction of Q1. In this bias condition the output impedance of the DS0056 is very low and will reduce the amplitude of the spikes.

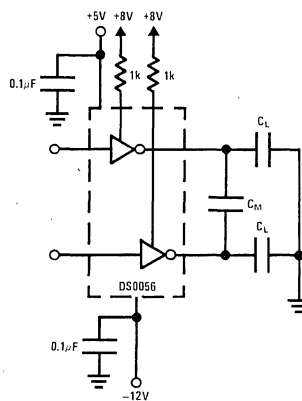


FIGURE 6. Use of DS0056 to Minimize Clock Line Cross Talk

Input Capacitive Coupling

Generally, MOS shift registers are powered from +5V and -12V supplies. A level shift from the TTL levels (+5V) to MOS levels (-12V) is therefore required. The level shift could be made utilizing a PNP transistor or zener diode. The disadvantage to dc level shifting is the increased power dissipation and propagation delay in the level shifting device. Both the DS0025, DS0026 and DS0056 utilize input capacitors when level shifting from

TTL to negative MOS capacitors. Not only do the capacitors perform the level shift function without inherent delay and power dissipation, but as will be shown later, the capacitors also enhance the performance of these circuits.

CONCLUSION

The practical aspects of driving MOS memories with low cost clock drivers has been discussed in detail. When the design guide lines set forth in this paper are followed and reasonable care is taken in circuit layout, the DS0025, DS0026 and DS0056 provide superior performance for most MOS input interface applications.

REFERENCES

1. Bert Mitchell, "New MOS Clock Driver for MOS Shift Registers," National Semiconductor, AN-18, March 1969.
2. John Vennard, "MOS Clock Drivers," National Semiconductor, MB-9, December 1969.
3. Dale Mrazek, "MOS Delay Lines," National Semiconductor, AN-25, April 1969.
4. Dale Mrazek, "MOS Clock Savers," National Semiconductor, MB-5.
5. Dale Mrazek, "Silicon Disc's Challenge Magnetic Disc Memories," EDN/EEE Magazine, Sept. 1971.
6. Richard Percival, "Dynamic MOS Shift Registers Can Also Simulate Stack and Silo Memories," Electronics Magazine, November 8, 1971.
7. Bapat and Mrazek, "Dynamic MOS Random Access Memory System Considerations," National Semiconductor, AN-50, August 1971.
8. Don Femling, "Using the MM5704 Keyboard Interface in Keyboard Systems," National Semiconductor, AN-52.

APPENDIX I

DS0025 Circuit Operation

The schematic diagram of the DS0025 is shown in Figure AI-1. With the TTL driver in the logic "0" state Q1 is "OFF" and Q2 is "ON" and the output is at approximately one V_{BE} below the V^+ supply.

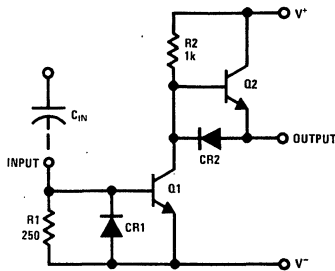


FIGURE AI-1. DS0025 Schematic (One-Half Circuit)

When the output of the TTL driver goes high, current is supplied to the base of Q1, through C_{IN} , turning it "ON." As the collector of Q1 goes negative, Q2 turns "OFF." Diode CR2 assures turn-on of Q1 prior to Q2's turn-off minimizing current spiking on the V^+ line, as well as providing a low impedance path around Q2's base emitter junction.

The negative voltage transition (to MOS logic "1") will be quite linear since the capacitive load will force Q1 into its linear region until the load is discharged and Q1 saturates. Turn-off begins when the input current decays to zero or the output of the TTL driver goes low. Q1 turns "OFF" and Q2 turns "ON" charging the load to within a V_{BE} of the V^+ supply.

Rise Time Considerations

The logic rise time (voltage fall) of the DS0025 is primarily a function of the ac load, C_L , the available input current and total voltage swing. As shown in Figure AI-2,

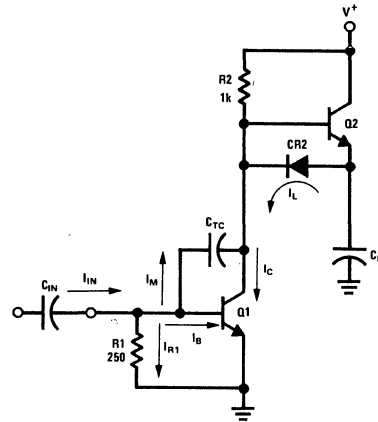


FIGURE AI-2. Rise Time Model for the DS0025

the input current must charge the Miller capacitance of Q1, C_{TC} , as well as supply sufficient base drive to Q1 to discharge C_L rapidly. By inspection:

$$I_{IN} = I_M + I_B + I_{R1} \tag{AI-1}$$

$$I_{IN} \cong I_M + I_B, \text{ for } I_M \gg I_{R1} \text{ \& \ } I_B \gg I_{R1}$$

$$I_B = I_{IN} - C_{TC} \frac{\Delta V}{\Delta t} \tag{AI-2}$$

If the current through R2 is ignored,

$$I_C = I_B h_{FEQ1} = I_L + I_M \tag{AI-3}$$

where:

$$I_L = C_L \frac{\Delta V}{\Delta t}$$

Combining equations AI-1, AI-2, AI-3 yields:

$$\frac{\Delta V}{\Delta t} [C_L + C_{TC} (h_{FEQ1} + 1)] = h_{FEQ1} I_{IN} \quad (A1-4)$$

or

$$t_r \cong \frac{[C_L + (h_{FEQ1} + 1)C_{TC}] \Delta V}{h_{FEQ1} I_{IN}} \quad (A1-5)$$

Equation (A1-5) may be used to predict t_r as a function of C_L and ΔV . Values for C_{TC} and h_{FE} are 10 pF and 25 respectively. For example, if a DM7440 with peak output current of 50 mA were used to drive a DS0025 loaded with 1000 pF, rise times of:

$$\frac{(1000 \text{ pF} + 250 \text{ pF}) (17V)}{(50 \text{ mA}) (20)}$$

or 21 ns may be expected for $V^+ = 5.0V$, $V^- = -12V$, Figure A1-3 gives rise time for various values of C_L .

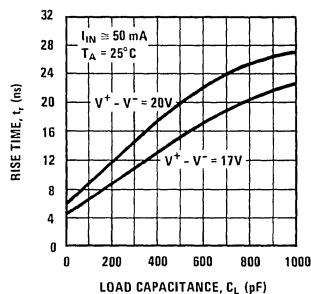


FIGURE A1-3. Rise Time vs C_L for the DS0025

Fall Time Considerations

The MOS logic fall time (voltage rise) of the DS0025 is dictated by the load, C_L , and the output capacitance of Q1. The fall time equivalent circuit of DS0025 may be approximated with the circuit of Figure A1-4. In actual

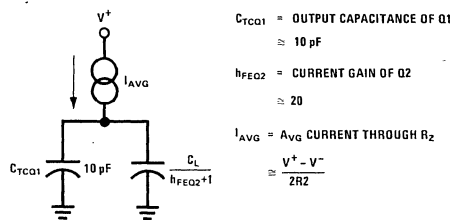


FIGURE A1-4. Fall Time Equivalent Circuit

practice, the base drive to Q2 drops as the output voltage rises toward V^+ . A rounding of the waveform occurs as the output voltage reaches to within a volt of V^+ . The result is that equation (A1-7) predicts conservative values of t_f for the output voltage at the beginning of the

voltage rise and optimistic values at the end. Figure A1-5 shows t_f as function of C_L .

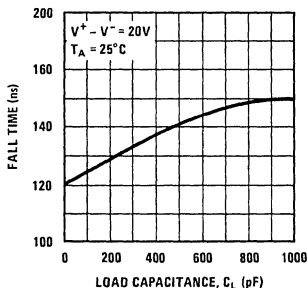


FIGURE A1-5. DS0025 Fall Time vs C_L

Assuming h_{FE2} is a constant of the total transition:

$$\frac{\Delta V}{\Delta t} = \frac{(V^+ - V^-)}{2R_2} \frac{1}{C_{TCQ1} + C_L/h_{FEQ1+1}} \quad (A1-6)$$

or

$$t_f \cong 2R_2 \left(C_{TCQ1} + \frac{C_L}{h_{FEQ1+1}} \right) \quad (A1-7)$$

DS0025 Input Drive Requirements

Since the DS0025 is generally capacitively coupled at the input, the device is sensitive to current not input voltage. The current required by the input is in the 50–60 mA region. It is therefore a good idea to drive the DS0025 from TTL line drivers, such as the DM7440 or DM8830. It is possible to drive the DS0025 from standard 54/74 series gates or flip-flops but t_{ON} and t_r will be somewhat degraded.

Input Capacitor Selection

The DS0025 may be operated in either the logically controlled mode (pulse width out \cong pulse width in) or C_{IN} may be used to set the output pulse width. In the latter mode a long pulse is supplied to the DS0025.

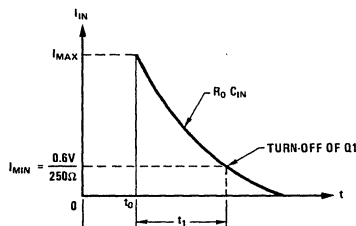


FIGURE A1-6. DS0025 Input Current Waveform

The input current is of the general shape as shown in *Figure A1-6*. I_{MAX} is the peak current delivered by the TTL driver into a short circuit (typically 50–60 mA). Q1 will begin to turn-off when I_{IN} decays below $V_{BE}/R1$ or about 2.5 mA. In general:

$$I_{IN} = I_{MAX} e^{-t/R0} C_{IN} \quad (A1-8)$$

where:

$R0$ = Output impedance of the TTL driver

C_{IN} = Input coupling capacitor

Substituting $I_{IN} = I_{MIN} = \frac{V_{BE}}{R1}$ and solving for t_1 yields:

$$t_1 = ROC_{IN} \ln \frac{I_{MAX}}{I_{MIN}} \quad (A1-9)$$

The total pulse width must include rise and fall time considerations. Therefore, the total expression for pulse width becomes:

$$t_{PW} \cong \frac{t_r + t_f}{2} + t_1$$

$$= \frac{t_r + t_f}{2} + ROC_{IN} \ln \frac{I_{MAX}}{I_{MIN}} \quad (A1-10)$$

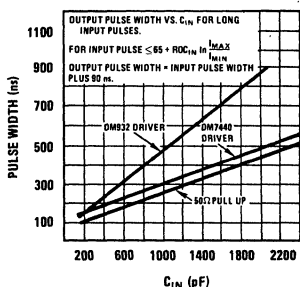


FIGURE A1-7. Output PW Controlled by C_{IN}

The logic "1" output impedance of the DM7440 is approximately 65Ω and the peak current (I_{MAX}) is about 50 mA. The pulse width for $C_{IN} = 2,200$ pF is:

$$t_{PW} \cong \frac{25 \text{ ns} + 150 \text{ ns}}{2} + (65\Omega)(2200 \text{ pF}) \ln \frac{50 \text{ mA}}{2.5 \text{ mA}} = 517 \text{ ns}$$

A plot of pulse width for various types of drivers is shown in *Figure A1-7*. For applications in which the output pulse width is logically controlled, C_{IN} should be chosen 2 to 3 times larger than the maximum pulse width dictated by equation (A1-10).

DC Coupled Operation

The DS0025 may be direct-coupled in applications when level shifting to a positive value only. For example, the MM1103 RAM typically operates between ground and +20V. The DS0025 is shown in *Figure A1-8* driving the address or precharge line in the logically controlled mode.

If DC operation to a negative level is desired, a level translator such as the DS7800 or DH0034 may be employed as shown in *Figure A1-9*. Finally, the level shift may be accomplished using PNP transistors as shown in *Figure A1-10*.

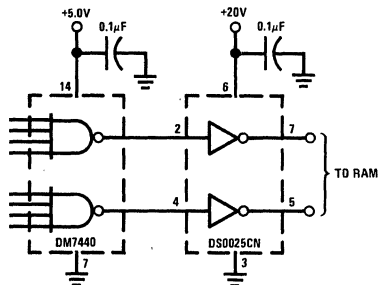


FIGURE A1-8. DC Coupled DS0025 Driving 1103 RAM

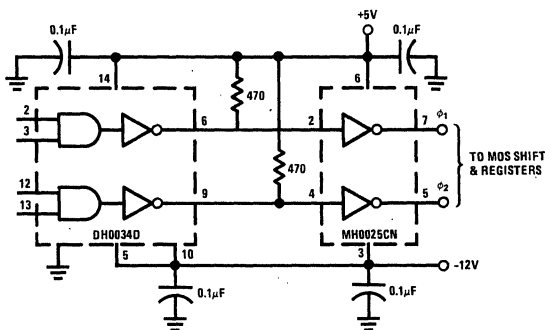


FIGURE A1-9. DC Coupled Clock Driver Using DH0034

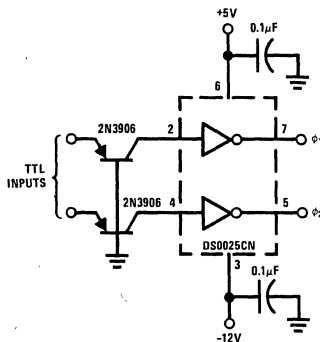


FIGURE A1-10. Transistor Coupled DS0025 Clock Driver

APPENDIX II

DS0026 Circuit Operation

The schematic of the DS0026 is shown in *Figure AII-1*. The device is typically ac coupled on the input and responds to input current as does the DS0025. Internal current gain allows the device to be driven by standard TTL gates and flip-flops.

With the TTL input in the low state Q1, Q2, Q5, Q6 and Q7 are "OFF" allowing Q3 and Q4 to come "ON." R6 assures that the output will pull up to within a V_{BE} of V^+ volts. When the TTL input starts toward logic "1," current is supplied via C_{IN} to the bases of Q1 and Q2 turning them "ON." Simultaneously, Q3 and Q4 are snapped "OFF." As the input voltage rises (to about 1.2V), Q5 and Q6 turn-on. Multiple emitter transistor Q5 provides additional base drive to Q1 and Q2 assuring their complete and rapid turn-on. Since Q3 and Q4 were rapidly turned "OFF" minimal power supply current spiking will occur when Q7 comes "ON."

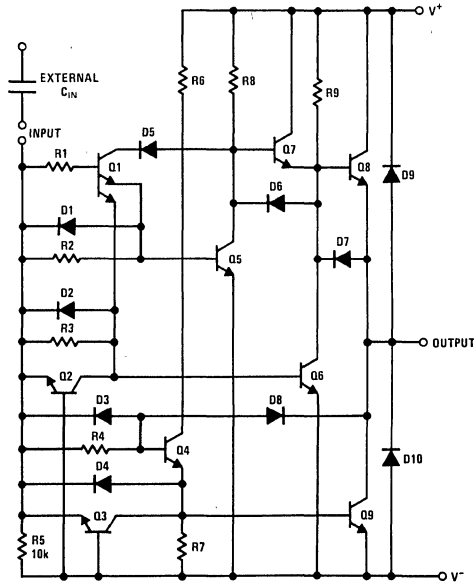


FIGURE AII-1. DS0026 Schematic (One-Half Circuit)

Q6 now provides sufficient base drive to Q7 to turn it "ON." The load capacitance is then rapidly discharged toward V^- . Diode D4 affords a low impedance path to Q6's collector which provides additional drive to the load through current gain of Q7. Diodes D1 and D2 prevent avalanching Q3's and Q4's base-emitter junction as the collectors of Q1 and Q2 go negative. The output of the DS0026 continues negative stopping about 0.5V more positive than V^- .

When the TTL input returns to logic "0," the input voltage to the DS0026 goes negative by an amount proportional to the charge on C_{IN} . Transistors Q8 and Q9 turn-on, pulling stored base charge out of Q7 and Q2 assuring their rapid turn-off. With Q1, Q2, Q6 and Q7 "OFF," Darlington connected Q3 and Q4 turn-on and rapidly charge the load to within a V_{BE} of V^+ .

Rise Time Considerations

Predicting the MOS logic rise time (voltage fall) of the DS0026 is considerably involved, but a reasonable approximation may be made by utilizing equation (AII-5), which reduces to:

$$t_r \cong [C_L + 250 \times 10^{-12}] \Delta V \tag{AII-1}$$

For $C_L = 1000 \text{ pF}$, $V^+ = 5.0V$, $V^- = -12V$, $t_r \cong 21 \text{ ns}$. *Figure AII-2* shows DS0026 rise times vs C_L .

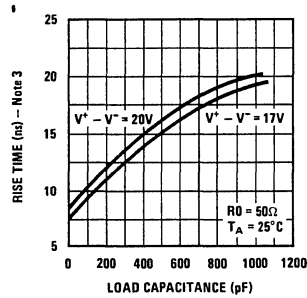


FIGURE AII-2. Rise Time vs Load Capacitance

Fall Time Considerations

The MOS logic fall time of the DS0026 is determined primarily by the capacitance Miller capacitance of Q5 and Q1 and R5. The fall time may be predicted by:

$$t_f \cong (2.2)(R5) \left(C_S + \frac{C_L}{h_{FE2}} \right) \tag{AII-2}$$

$$\cong (4.4 \times 10^3) \left(C_S + \frac{C_L}{h_{FE2}} \right)$$

where:

$$C_S = \text{Capacitance to ground seen at the base of Q3}$$

$$= 2 \text{ pF}$$

$$h_{FE2} = (h_{FEQ3} + 1)(h_{FEQ4} + 1)$$

$$\cong 500$$

For the values given and $C_L = 1000 \text{ pF}$, $t_f \cong 17.5 \text{ ns}$. *Figure AII-3* gives t_f for various values of C_L .

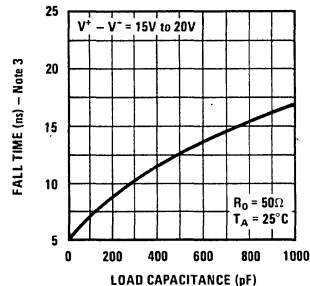


FIGURE AII-3. Fall Time vs Load Capacitance

DS0026 Input Drive Requirements

The DS0026 was designed to be driven by standard 54/74 elements. The device's input characteristics are shown in *Figure AII-4*. There is breakpoint at $V_{IN} \cong 0.6V$ which corresponds to turn-on of Q1 and Q2. The input current then rises with a slope of about 600Ω ($R2 \parallel R3$) until a second breakpoint at approximately 1.2V is encountered, corresponding to the turn-on of Q5 and Q6. The slope at this point is about 150Ω ($R1 \parallel R2 \parallel R3 \parallel R4$).

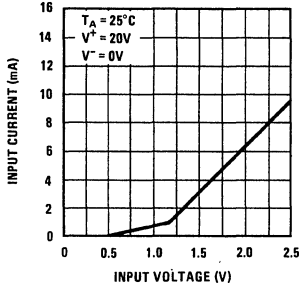


FIGURE AII-4. Input Current vs Input Voltage

The current demanded by the input is in the 5–10 mA region. A standard 54/74 gate can source currents in excess of 20 mA into 1.2V. Obviously, the minimum "1" output voltage of 2.5V under these conditions cannot be maintained. This means that a 54/74 element must be dedicated to driving 1/2 of a DS0026. As far as the DS0026 is concerned, the current is the determining turn-on mechanism not the voltage output level of the 54/74 gate.

Input Capacitor Selection

A major difference between the DS0025 and DS0026 is that the DS0026 requires that the output pulse width be logically controlled. In short, the input pulse width \cong output pulse width. Selection of C_{IN} boils down to choosing a capacitor small enough to assure the capacitor takes on nearly full charge, but large enough so that the input current does not drop below a minimum level to keep the DS0026 "ON." As before:

$$t_1 = R0C_{IN} \ln \frac{I_{MAX}}{I_{MIN}} \tag{AII-3}$$

or

$$C_{IN} = \frac{t_1}{R0 \ln \frac{I_{MAX}}{I_{MIN}}} \tag{AII-4}$$

In this case R0 equals the sum of the TTL gate output impedance plus the input impedance of the DS0026 (about 150Ω). I_{MIN} from *Figure AII-5* is about 1 mA. A standard 54/74 series gate has a high state output impedance of about 150Ω in the logic "1" state and an output (short circuit) current of about 20 mA into 1.2V. For an output pulse width of 500 ns,

$$C_{IN} = \frac{500 \times 10^{-9}}{(150\Omega + 150\Omega) \ln \frac{20 \text{ mA}}{1 \text{ mA}}} = 560 \text{ pF}$$

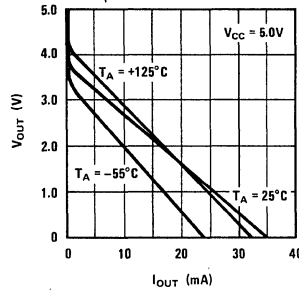


FIGURE AII-5. Logical "1" Output Voltage vs Source Current

In actual practice it's a good idea to use values of about twice those predicted by equation (AII-4) in order to account for manufacturing tolerances in the gate, DS0026 and temperature variations.

A plot of optimum value for C_{IN} vs desired output pulse width is shown in *Figure AII-6*.

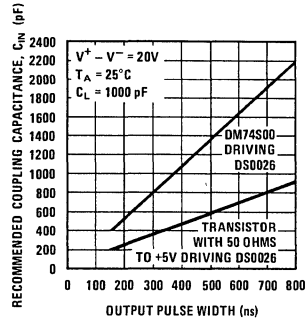


FIGURE AII-6. Suggested Input Capacitance vs Output Pulse Width

DC Coupled Applications

The DS0026 may be applied in direct coupled applications. *Figure AII-7* shows the device driving address or pre-charge lines on an MM1103 RAM.

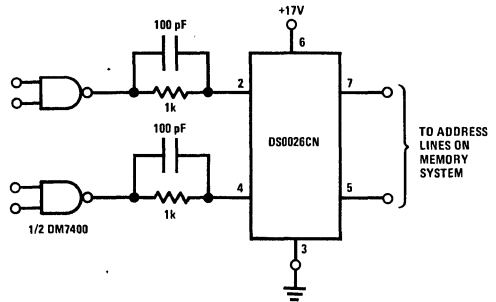


FIGURE AII-7. DC Coupled RAM Memory Address or Precharge Driver (Positive Supply Only)

For applications requiring a dc level shift, the circuit of Figure A11-8 or A11-9 are recommended.

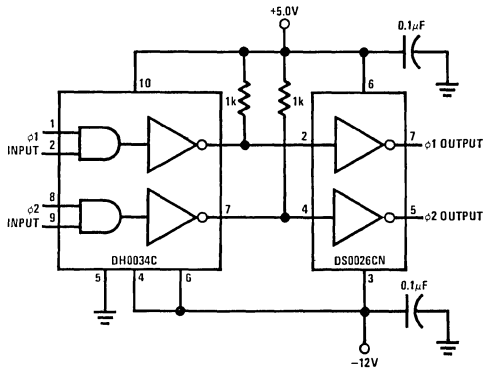


FIGURE A11-8. Transistor Coupled MOS Clock Driver

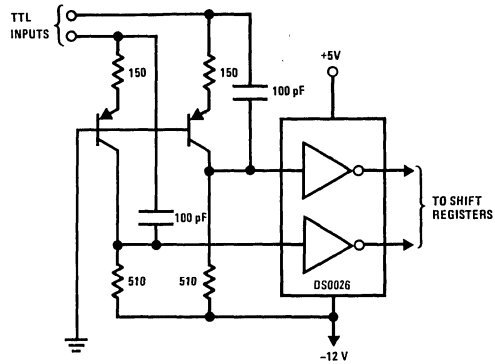


FIGURE A11-9. DC Coupled MOS Clock Driver

APPENDIX III

MOS Interface Circuits

MOS Clock Drivers

MH0007	Direct coupled, single phase, TTL compatible clock driver.
MH0009	Two phase, direct or ac coupled clock driver.
MH0012	10 MHz, single phase direct coupled clock driver.
MH0013	Two phase, ac coupled clock driver.
DS0025C	Low cost, two phase clock driver.
DS0026C	Low cost, two phase, high speed clock driver.
DS3671	Dual bootstrapped MOS driver.
DS3674	Quad MOS clock driver.
DS75361	Dual TTL-to-MOS driver.
DS75365	Quad TTL-to-MOS driver.

MOS RAM Memory Address and Precharge Drivers

DS0025C	Dual address and precharge driver.
DS0026C	Dual high speed address and precharge driver.

TTL to MOS Interface

DH0034	Dual high speed TTL to negative level converter.
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DS8800	Dual TTL to negative level converter.
DS8810/DS8812/DS8819	Open collector TTL to positive high level MOS converter gates.
DS88L12	Active pull-up TTL to positive high level MOS converter gates.
DS3645/DS3675	Hex TRI-STATE [®] MOS driver.
DS3647/DS3677	Quad TRI-STATE MOS driver I/O register.
DS3648/DS3678	TRI-STATE MOS driver multiplexer.
DS3649/DS3679	Hex TRI-STATE MOS driver.
DS36149/DS36179	Hex TRI-STATE MOS driver.

MOS to TTL Converters and Sense Amps

DS75107,	Dual sense amp for MM1103 1k
DS75207	MOS RAM memory.

Voltage Regulators for MOS Systems

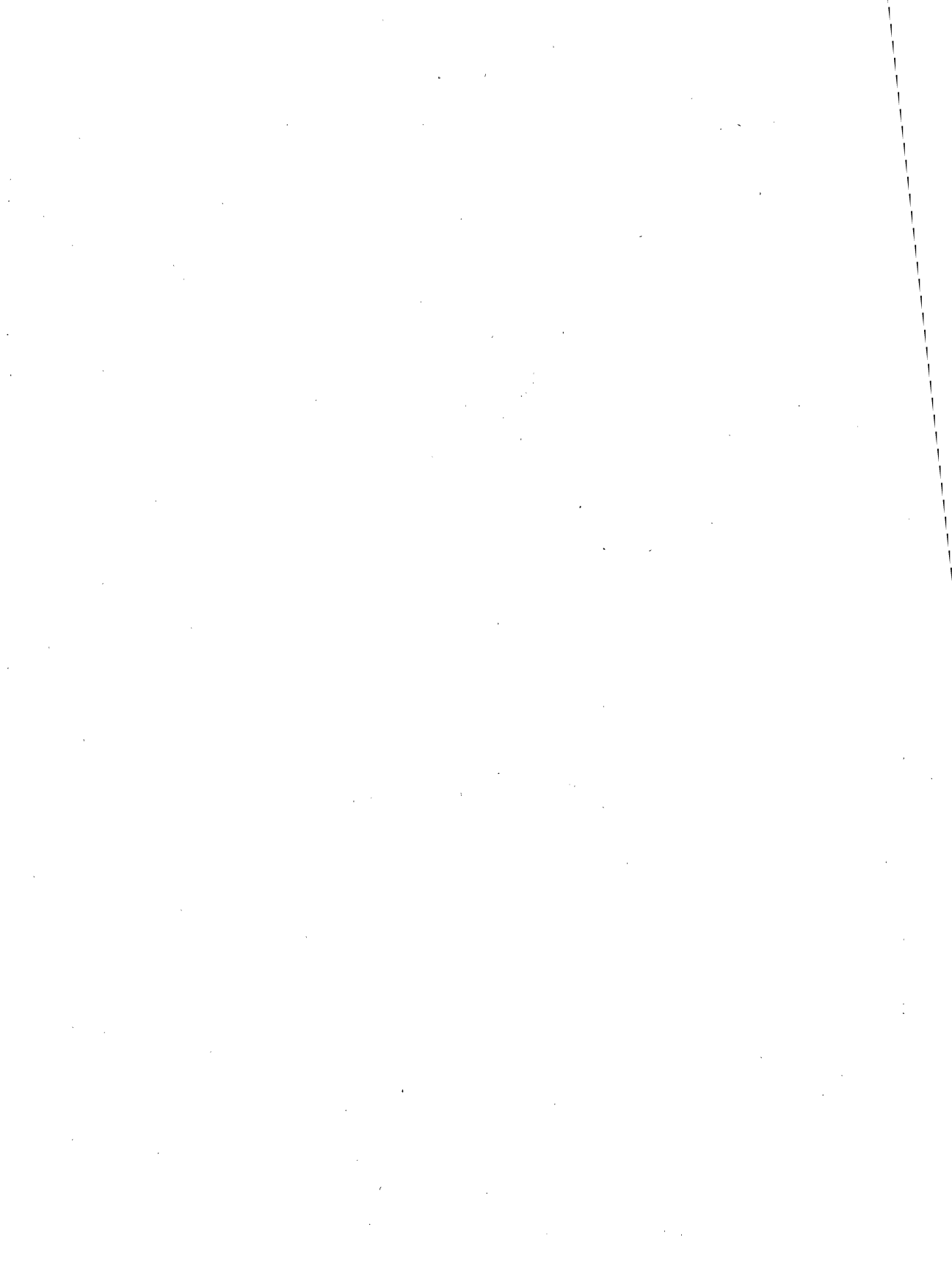
LM309, LM340 Series	Positive regulators.
LM320 Series	Negative regulators.
LM325 Series	Dual +/- regulators.



Section 7 Dynamic Memory Support



DEVICE	DESCRIPTION	PAGE NUMBER
Family Introduction		
AN-302	DP8400 Family of Memory Interface Circuits	7-3
Dynamic RAM Controllers and Drivers		
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	Single-Chip Controllers Cover All RAMs from 16k to 256k	7-20
DP8408	Dynamic RAM Controller/Driver	7-26
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AN-309	Interfacing the DP8408/09 to Various Microprocessors	7-177
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The DP8400 Family of Memory Interface Circuits

National Semiconductor
Application Note 302
Charles Carinalli
Mike Evans
March 1983

INTRODUCTION

The rapid development in dynamic random access memory (DRAM) chip storage capability, coupled with significant component cost reductions, has allowed designers to build large memory arrays with high performance specifications. However, the development of memory arrays continues to have a common set of problems generated by the complex timing and refresh requirements of DRAMs. These include: how to quickly drive the memories to take advantage of their speed, minimization of board space required by the support circuitry and the need for error detection and correction. Unfortunately, these problems must be addressed with each new system design. Full system solutions will vary greatly, depending on the DRAM array size, memory speed, and the processor.

This application note introduces a complete family of DRAM support circuits that provides a straightforward solution to the above problems while allowing a high degree of flexibility in application with little or no performance penalty. The DP8400 family (Table I) includes DRAM controllers, an expandable error detection/correction circuit, octal address buffers and system control circuits. The LSI blocks are designed with flexible interfaces, making application possible with all existing DRAMs including the recently announced 256Ks. Additionally, interface is easy to all popular microprocessors with memory word widths possible from 8 to 80 bits.

TABLE I. DP8400 FAMILY MEMBERS

DP8400	Expandable Error Checker/Corrector
DP8408, DP8409	DRAM Controllers
DP84240, DP84244	DRAM Buffer Drivers
DP84300 Series	Microprocessor Interface Circuits

FULL FUNCTION DRAM CONTROLLER

The heart of any DRAM array design is the controller function. Previous LSI controllers supplied a minimum function of address multiplexing with an on-board refresh counter. This required external delay line timing and logic to control memory access, additional logic to perform memory refresh, and external drivers to drive the capacitive memory array. The complete solution results in significant access delay in relation to DRAM speeds and skews in output sequencing, as well as a large component count.

A previous LSI solution brought much of this logic on-chip. However, it is limited in application to certain microprocessors and has the disadvantage of all access timing originating from an external clock, whose phase uncertainty generates a delay in actually knowing when an access has started.

The DP8409 multi-mode dynamic RAM controller/driver is the first controller to resolve all of these problems. This Schottky bipolar device provides the flexibility of external access control, along with automatic access timing generation, without the need for an external timing generator clock. In addition, on-board capacitive drivers allow direct drive for over 88 DRAMs. With the simple addition of refresh clocks, the circuit can perform hidden refresh automatically. But possibly one of the DP8409's most important advantages is its upgradability for use with 256K DRAMs.

All Control On-Chip

Figure 1 is a block diagram of the DP8409. The ADS input strobes the parallel memory address into the row latches R0-8, the column latches C0-8, and bank select B0 and B1. The nine output drivers may be multiplexed between the row or column input latches, or the 9-bit on-chip refresh counter. One of four RAS outputs is selected during an access cycle by setting the bank select inputs B0 or B1. All four RAS outputs are active during refresh. Either external or automatic control is available on-chip for the CAS output, while an on-chip buffer is provided to minimize skew associated with WE output generation.

All DRAM address and control outputs on the DP8409 can directly drive in excess of 500 pF, or the equivalent of 88 DRAMs (4 banks of 22 DRAMs). All output drivers are closely matched, significantly reducing output skew. Each output stage has symmetrical high and low logic level drive capability, insuring matched rise and fall time characteristics.

Flexibility and Upgradability to 256K

The 9 multiplexed address outputs and 9-bit internal refresh counter of the DP8409 not only guarantee its use with all current DRAMs (16K and 64Ks), but also enable direct addressing capability for the forthcoming 256K DRAMs. Careful design of memory boards, using the current 64K DRAMs with the DP8409, will insure direct upgradability to 256K DRAMs. This can be done by simply allowing for board address extension by two bits and designing the ninth address trace (Q8) of the DP8409 to connect to pin 1 of the DRAMs (A8). This is, in general, a nonconnected pin in 64Ks and the ninth address in 256Ks. All that need be done is to remove the 64Ks and replace them with 256Ks, thereby increasing the memory on the same board by a 4 to 1 ratio. The resulting development cost saving can be significant.

Three mode pins (M0, M1 and M2) offer externally selectable modes of operation, a key reason for the DP8409's application flexibility (Table II). The operational modes are divided between external and automatic memory control. Modes 0, 3b, and 4 provide full control of access and refresh for systems with external memory controllers or for special purpose applications. Here all timing can be directly controlled by the external system as shown in Figure 2.

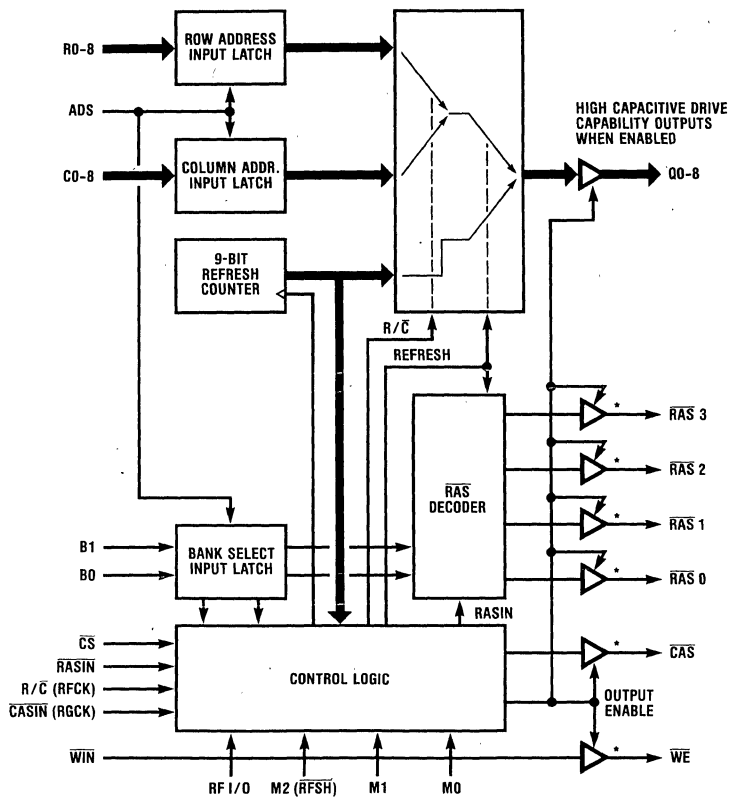


FIGURE 1. DP8409 Block Diagram

TABLE II. DP8409 MODE SELECT OPTIONS

Mode	(RFSH) M2	M1	M0	Mode of Operation	Conditions
0	0	0	0	Externally Controlled Refresh	RF I/O = \overline{EOC}
1	0	0	1	Auto Refresh—Forced	RF I/O = Refresh Request (\overline{RFRQ})
2	0	1	0	Internal Auto Burst Refresh	RF I/O = \overline{EOC}
3a	0	1	1	All \overline{RAS} Auto Write	RF I/O = \overline{EOC}
3b	0	1	1	Externally Controlled All \overline{RAS} Access	All \overline{RAS} Active
4	1	0	0	Externally Controlled Access	
5	1	0	1	Auto Access, Slow t_{RAH} , Hidden Refresh	
6	1	1	0	Auto Access, Fast t_{RAH}	
7	1	1	1	Set End of Count	

Modes 1, 5 and 6 provide on-chip automatic access sequencing with hidden refresh capability. A graphic example of the automatic access modes of the DP8409 is shown in Figure 3. All DRAM access timing and control is generated from one input strobe, \overline{RASIN} ; no external clock is required. On-chip delays insure proper address and control sequencing once the valid parallel address is presented to the fall-through input latches of the DP8409. When the \overline{RASIN} transitions high-to-low, the decoded \overline{RAS} output transitions low, strobing the row address into the DRAM array. An on-chip delay automatically generates a guaranteed selectable (mode 5 or 6) row address hold time. At this point, the DP8409 switches the address outputs from the row latch to the column latch. Then another on-chip delay generates a guaranteed column address

set-up time before \overline{CAS} , so that the \overline{CAS} output automatically strobbs the column address into the DRAM array. Read or write cycles are controlled by the system through independent control of the \overline{WE} buffer that is provided on-chip to minimize delay skewing. The automatic access mode makes the dynamic RAM appear static with respect to access timing. In this mode, only one signal, \overline{RASIN} , is needed after valid parallel addresses are presented to the DP8409 to initiate proper access sequencing. Access timing (\overline{RASIN} to \overline{CAS}), with full output loading of 88 DRAMs in the auto access mode, is determined by the dash number given on the DP8409 data sheet. All performance characteristics are specified over the full operating temperature and supply ranges.

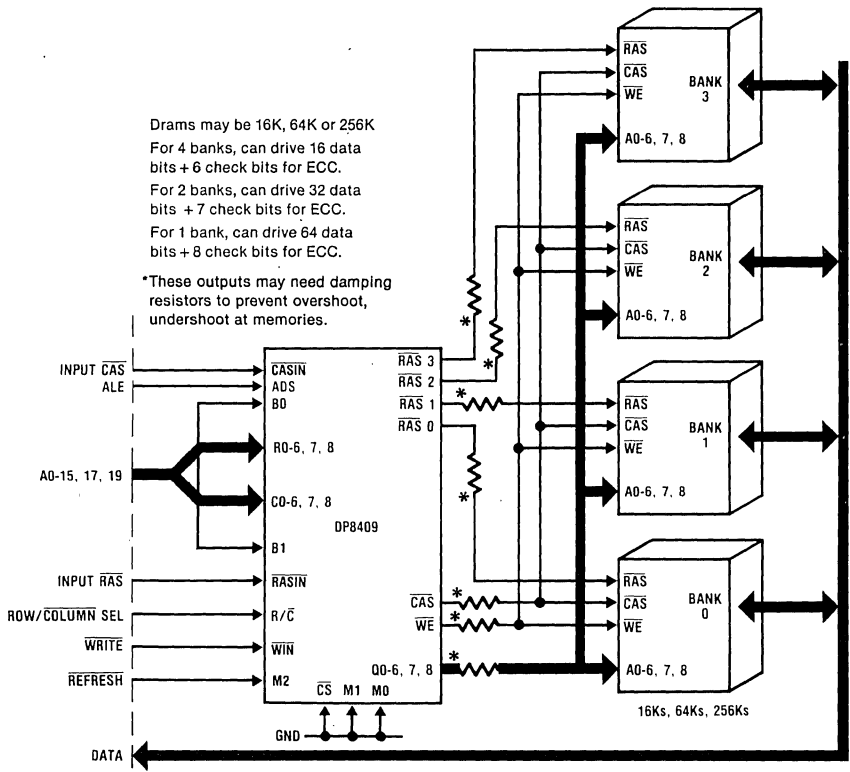


FIGURE 2. Typical Application of DP8409 Using External Control and Refresh in Modes 0 and 4

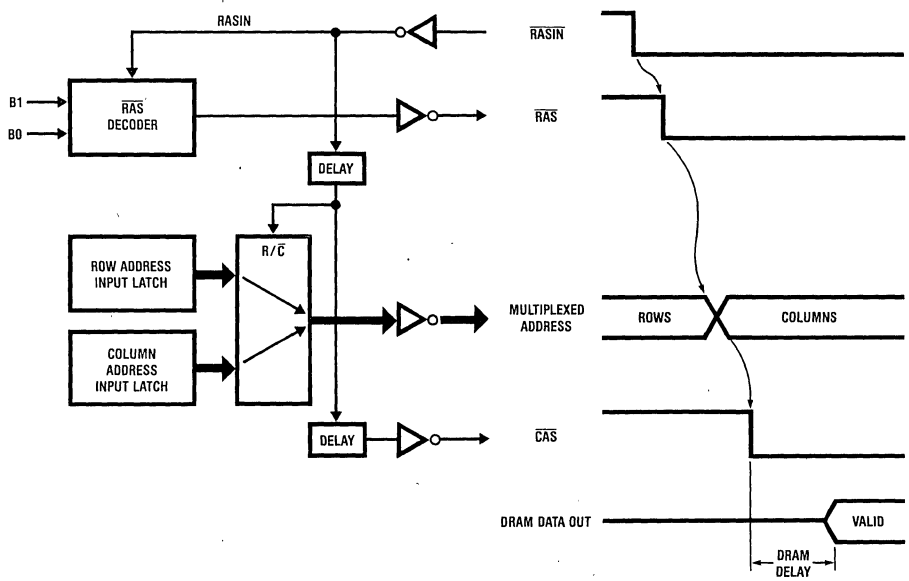


FIGURE 3. This figure demonstrates the automatic accessing capability of the DP8409. Only one strobing edge, $\overline{\text{RASIN}}$, is required for generation of all DRAM access timing signals. This is accomplished with on-chip delay generators, eliminating the need for external delay lines. No access timing clock is necessary.

Refreshing

The DP8409 also provides hidden refresh capability while in one of the automatic access modes (Figure 4). In this mode, it will automatically perform a refresh without the system being interrupted. To do this, the DP8409 requires two clock signals, refresh clock (RFCK) which defines the refresh period (usually 16 μ s), and $\overline{\text{RAS}}$ generator clock (RGCK), which is typically the microprocessor clock.

Highest priority is given to hidden refreshing through use of level sensing of RFCK. A refresh cycle begins when RFCK transitions to a high level. If during the time RFCK is high the DP8409 is deselected ($\overline{\text{CS}}$ in the high state) and the processor is accessing another portion of the system such as another memory segment, or ROM, or a peripheral, then a hidden refresh is performed. When a read or write cycle is initiated by the processor, the $\overline{\text{RASIN}}$ input on the DP8409 transitions low. With $\overline{\text{CS}}$ high, this causes the present state of the internal refresh counter to be placed on the address outputs, followed by the four $\overline{\text{RAS}}$ outputs transitioning low, strobing the refresh address into the DRAM array. When the cycle ends, $\overline{\text{RASIN}}$ will terminate, thus forcing the $\overline{\text{RAS}}$ outputs back to their inactive state and ending the hidden refresh. The refresh counter is then incremented and another microprocessor cycle can begin immediately. However, to save power, the DP8409 will allow only one hidden refresh to occur during a given RFCK cycle.

In the event that a hidden refresh does not occur, the DP8409 must force a refresh before the RFCK's next positive-going transition. The system is notified after the

negative-going RFCK transition that a hidden refresh has not occurred, via the refresh request output (RF I/O pin). The system acknowledges the request for a forced refresh by setting M2 (refresh) low on the DP8409 and preventing further access to the DP8409. The DP8409 then uses RGCK to generate an automatic forced refresh. The refresh request pin then returns to the inactive state, and the DP8409 allows the processor to take full system control after the forced refresh has been completed.

OCTAL MEMORY DRIVERS

When the memory array becomes large and the 88-DRAM drive capability of the DP8409 becomes insufficient, additional address and control buffers are required. However, like any other element in a DRAM system, selection of the improper driver can have significant impact on system performance.

In the past, this function has been performed using Schottky logic family circuits such as the DM74S240 octal inverter or the DM74S244 octal buffer. The output stages of these devices have good drive capability, but their performance with heavy capacitive loads is not ideal for DRAM arrays. The key disadvantage of these devices is their nonsymmetrical rise and fall time characteristics and their long propagation delays with heavy load capacitance. The former is a result of impedance mismatch in the upper and lower output stages. The latter stems from process capability and circuit design techniques not tailored to the DRAM application. The combined result of all these factors is increased output skew in address and control lines when these devices are used as buffers.

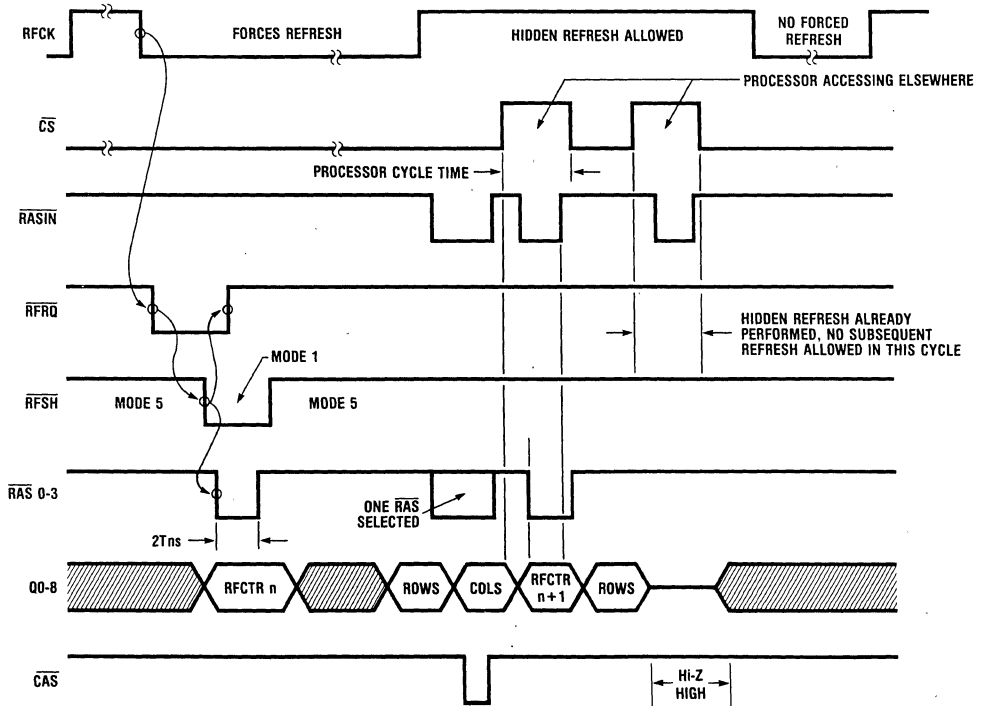


FIGURE 4. Hidden and Forced Refresh Timing of the DP8409

Two new devices are now available for this application. The DP84240 is pin and function compatible with the DM74S240. The DP84244 is likewise compatible with the DM74S244. However, this is where the similarity between the devices ends. Both the DP84240 and the DP84244 have been designed specifically to drive DRAM arrays. Figure 5 shows a typical application of the DP84244, used in conjunction with the DP8409, to drive a very large memory array.

Figures 6a, 6b show some typical performance curves for these circuits. Note that, at over 500 pF, the propagation delay through these drivers is on the order of 15 ns. This delay includes propagation delay and rise or fall time. Even with this high speed, chip power dissipation

is still maintained at a reasonable level as demonstrated by the graphs shown in Figures 7a, 7b of power versus frequency.

The DP84240 and the DP84244 are fabricated on a high performance oxide-isolated Schottky bipolar process. Special circuit techniques have been used to minimize internal delays and skews. Additionally, both rise and fall time characteristics track closely as a function of load capacitance. This has been accomplished through impedance matching of the upper and lower output stages. The result of these characteristics is a substantial reduction of skew in both the address and control lines to the DRAM array.

*Resistor required depends on DRAM load. See AN-305 "Precautions to Take When Driving Memories."

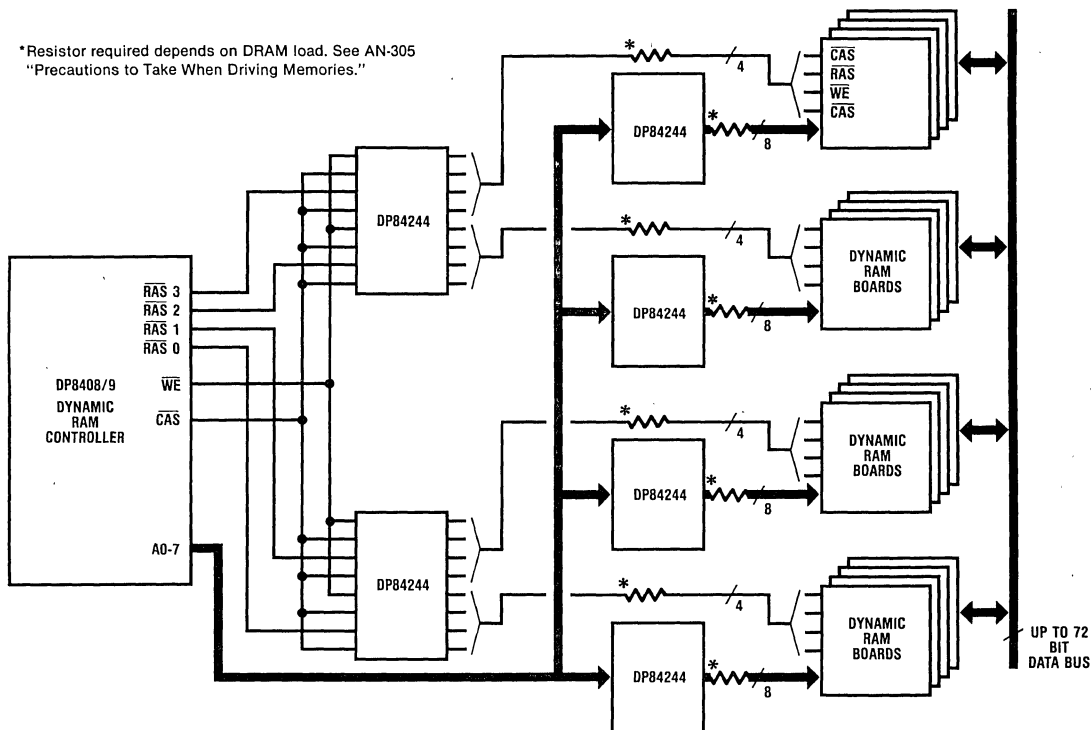


FIGURE 5. The DP84244 Used as a Buffer in a Large Memory Array (greater than 88 DRAMs) Controlled by the DP8409

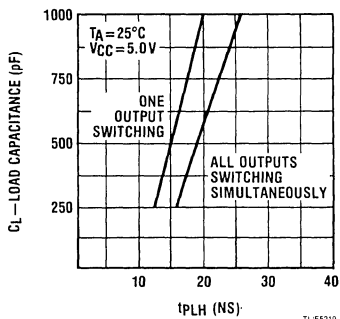


FIGURE 6a. t_{PLH} Measured to 2.7V on Output vs. C_L

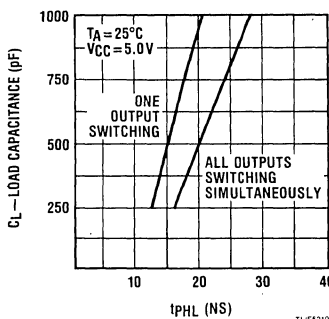


FIGURE 6b. t_{PHL} Measured to 0.8V on Output vs. C_L

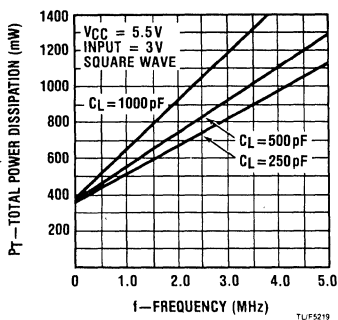


FIGURE 7a. Typical Power Dissipation for DP84240 at $V_{CC} = 5.5V$ (All 8 drivers switching simultaneously)

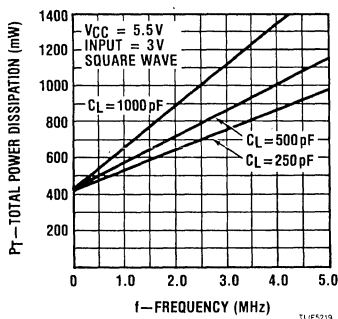


FIGURE 7b. Typical Power Dissipation for DP84244 at $V_{CC} = 5.5V$ (All 8 drivers switching simultaneously)

The output stages of the DP84240 and the DP84244, although well matched, are relatively low impedance. Output impedance is under 10Ω . Some DRAM arrays will require the addition of damping resistors in series with the outputs of the drivers. These damping resistors are used to minimize undershoot which may have a harmful effect on the DRAMs if allowed to become large. This undershoot is caused by the high transient currents from the drivers necessary to drive the capacitive loads. These high currents pass through a distributed inductive/capacitive circuit created by the board traces and the DRAM load, causing the undershoot.

The damping resistor has specifically not been placed on-chip because its value is dependent on the DRAM array size and board layout. In fact, address lines will quite often require a different resistor value from the DRAM control lines. The resistor must be tuned for a particular board layout since too high a resistor will produce an excessively slow edge and too low a resistor will not remove the undershoot. Values for damping resistors may vary from 15Ω to 150Ω , depending on the application. Placing any value of damping resistor on-chip, other than a value less than the minimum, severely restricts the application of these high performance circuits.

Another key advantage of both the DP84240 and the DP84244 is their low input capacitance. Previous address buffer/drivers (such as the DM74S240/244) have high input capacitance. Fast edges at the inputs of these drivers become slower and distorted due to this dynamic input

capacitance. This problem must be factored as an additional delay through these drivers—a delay not shown by the data sheet specifications. Additionally, the problem becomes increasingly severe as multiple driver inputs are used in parallel for bus expansion applications.

Both the DP84240 and the DP84244 are designed to significantly reduce both static and dynamic input capacitance. When these devices are driven with standard logic circuits, no appreciable overhead delay need be added to the basic device delay specifications due to input pulse distortion.

ERROR CORRECTION

The determination of whether a DRAM system requires error correction must be resolved early in the system design. A positive answer to this question may have far-reaching impact on board development time and component cost. It is clear, however, that such a decision cannot be taken lightly.

The type and origin of errors in DRAM systems are many and can result from a number of sources (Table III). Current estimates of soft error rates due to alpha particles in 64K RAMs indicate some hope that these error rates will be similar or possibly better than those found in 16K DRAMs—but the facts are still somewhat unclear. However, it is clear that the introduction in the near future of 256K DRAMs with even smaller memory cells and greater chip densities will place a significant challenge on DRAM chip designers to keep these rates down. It is believed by some that error correction may become mandatory in future DRAM system designs. Currently, the decision to add error correction is not so straightforward. It depends on many factors, not the least of which is the end user's perception of its value to system uptime and reliability.

TABLE III. THE SOURCES AND TYPES OF MEMORY ERRORS

Error Type	Sources	System Action
Soft	<ul style="list-style-type: none"> • Alpha particles • System noise • Chip patterns • Power glitches 	Temporary system error—may be overwritten with a low probability of repetition
Hard	<ul style="list-style-type: none"> • Stuck memory bit • Memory chip interface • Interface circuit failure 	Permanent failure—may act as logic 1 or 0

Generally, error correction will always be found in highly reliable systems using DRAMs, such as process control equipment, banking terminals, and military systems where high data integrity and minimum downtime are priorities. However, the importance of error correction has grown substantially, to the point that it is now used as a selling feature in the vast majority of large memory-based systems. In fact, some major computer houses have adopted guidelines for use by their designers in the development of DRAM arrays. A somewhat common set has been found—if the memory array is on the order of $1/4$ million bytes, then word parity should be used. This permits the detection of single bit errors but does not allow error correction. When the total memory approaches $1/2$ million bytes, then double bit error detection and single bit error correction should be added.

The decision to add error correction to a system is costly, both in memory overhead and control hardware. Table IV

TABLE IV. CHECK BIT OVERHEAD FOR MULTIPLE BIT ERROR DETECTION AND SINGLE BIT ERROR CORRECTION

Number of Bits in Memory Data Word	Number of Check Bits Required	Percentage of Excess Memory
8	5	63%
16	6	38%
24	6 (7)	25% (29%)
32	7	22%
48	7 (8)	15% (17%)
64	8	13%

Note: The number stated assumes the use of the DP8400; the number in parentheses is required by other error correction circuits.

lists the number of additional memory chips required to support single bit error correction and double bit error detection as a function of the memory data word width.

This table also shows the percentage of DRAM overhead required to implement this function. Adding error correction also increases the memory access delay, since the information contained in the overhead chips must be analyzed in each read and generated in each write operation.

DP8400 Expandable Error Correction Chip

The DP8400 expandable error checker/corrector is shown in block diagram form in Figure 8. This circuit offers a high degree of flexibility in applications which range from 8-bit

to 80-bit data words. It is a 16-bit chip that is easily expandable with the simple addition of more DP8400s for each 16-bit word increment.

Figures 9a, 9b and 9c demonstrate its basic operation in the write and read memory access cycles. Figure 9a shows the normal write cycle, where system data is used by the DP8400 to generate parity bits, called check bits, based on certain combinations of the data bits. This combination is defined by the DP8400's matrix shown in Figure 10. Whenever a '1' occurs in any row, the corresponding input data bit at the top of the column helps determine the parity for that check bit labeled at the end of the row. These check bits are written along with the data at the same memory address. Also, during a memory write cycle the DP8400 checks system byte parity. This is parity associated with the data bytes transmitted between the processor and the memory card. This is an optional feature that may prove very valuable in multiple board memory systems.

Sometime later a read will occur at this same memory address. The reading of memory data may be performed in two ways, as shown in Figures 9b and 9c. In the read cycle, the DP8400 uses the data read from memory and internally regenerates check bits using the same matrix. These newly generated check bits are then compared (using X-OR gates) with the check bits read from memory to detect errors. The result of this comparison is called a syndrome word. Any differences in the generated versus read check bits will result in at least one syndrome bit true. This indicates an error in either the read data or check bit field or both.

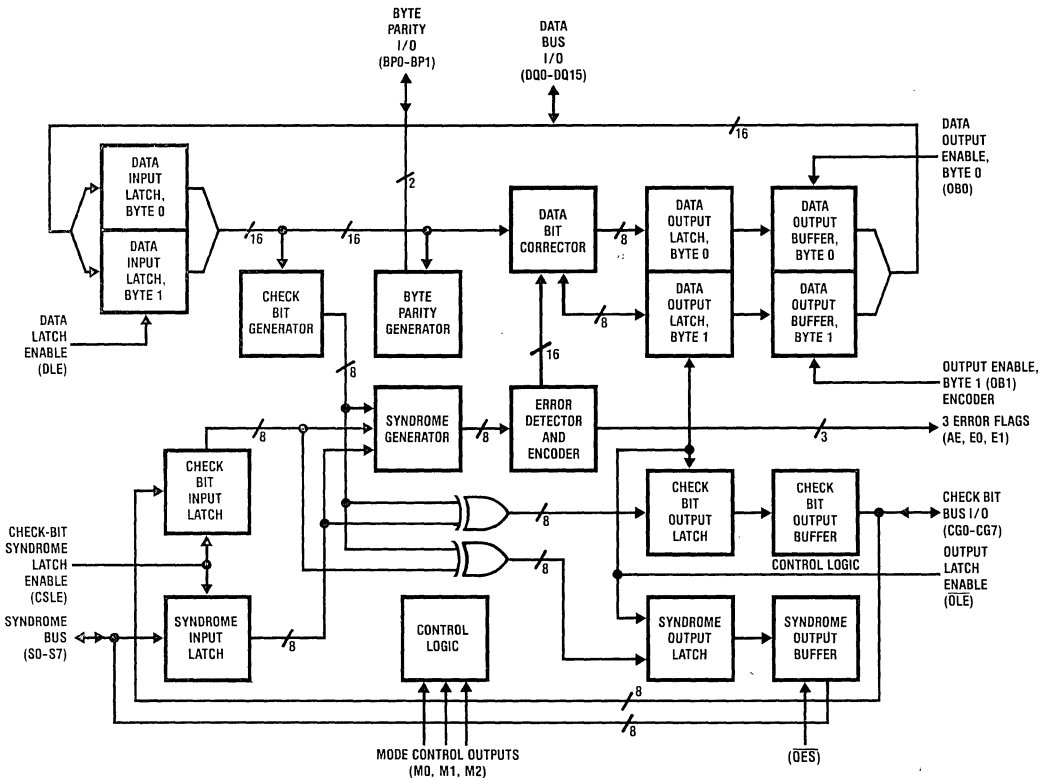


FIGURE 8. DP8400 Simplified Block Diagram

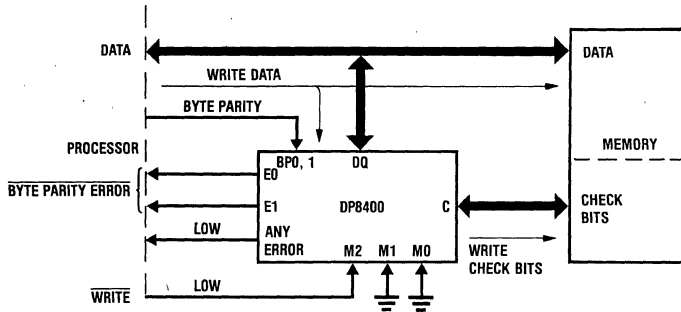


FIGURE 9a. Normal Write Mode with DP8400

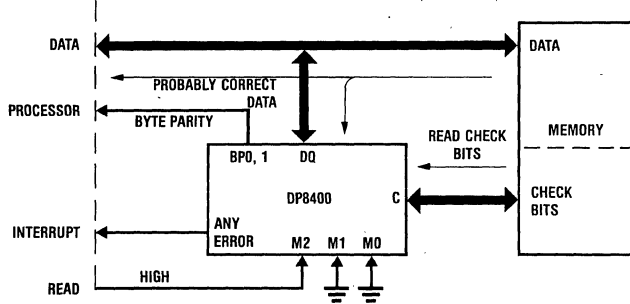


FIGURE 9b. Normal Read Mode Using the Error Monitoring Method with the DP8400

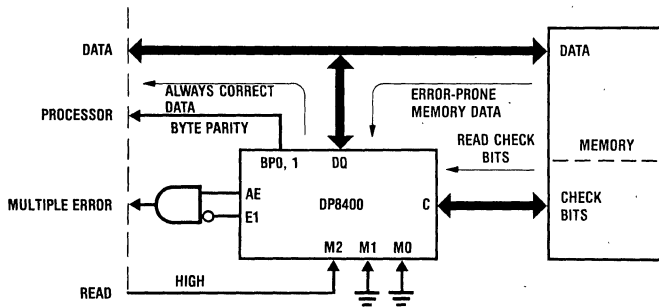


FIGURE 9c. Normal Read Mode Using the Always Correct Method with the DP8400

										1	1	1	1	1	1	} DQ0-15		
										9	0	1	2	3	4		5	
										GENERATE CHECK BITS →								
GENERATED SYNDROMES	0	0	0	1	1	1	1	1	1	0	1	1	1	0	1	1	1	0
	1	0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	1
	2	1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	1
	3	0	1	1	0	0	0	0	1	1	1	1	1	0	1	0	1	1
	4	1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	4
	5	1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	5
	4	8	9	7	5	1	3	9	E	B	D	3	C	7	F	F	0	
	3	3	2	0	2	3	2	1	3	0	0	1	2	3	2	1	1	

HEXADECIMAL EQUIVALENT OF SYNDROME BITS

* C2, C3 generate odd parity

FIGURE 10. DP8400 Matrix

A key advantage of the DP8400 is that it has three error flags detailing the type of error occurrence. These are generated using the syndrome word in the manner shown in Figure 11. The resulting error type identifications are shown in Table V. The three error flags allow complete error type identification, plus the unique determination of double bit errors, which will be key during the discussion of double bit error correction. Also, on a memory read, the DP8400 generates byte parity bits for transmission to the processor along with the data.

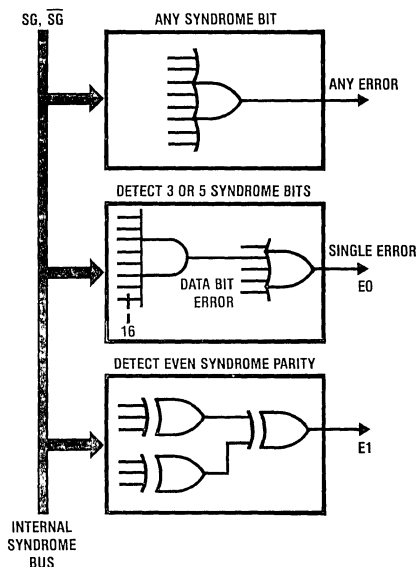


FIGURE 11. The DP8400 Error Encoder Generating 3 Error Flags

TABLE V. ERROR FLAGS AFTER NORMAL READ

AE	E1	E0	Error Type
0	0	0	No error
1	1	0	Single check bit error
1	1	1	Single data error
1	0	0	Double-bit error
All Others			Invalid conditions

There are two basic memory read methods that may be used with the DP8400. The first is shown in Figure 9b and is called the error monitoring method. Here, the read data is assumed to be correct and the processor immediately acts on the data. If the DP8400 detects an error, the processor is interrupted using the any error flag (AE). Using this method, there is no detection delay in most memory reads since errors seldom occur, but when an error does occur, the processor must be capable of accepting an interrupt and a read cycle extension to obtain the corrected data from the DP8400.

A second approach is called the always correct method, Figure 9c. In this case, the data is always assumed to be in

error and the processor always waits for the DP8400 to analyze whether an error exists. Then the corrected or unchanged data is read from the DP8400. Although this method results in longer memory read time, every memory read will always be of the same delay except when a double error occurs. The selection of which method to use depends on many factors, including the processor, system structure, and performance.

Double Bit Error Correct

The probability of double bit errors in DRAM systems is relatively low, but as memory array sizes grow, the occurrence of these error types must be considered. Adopting certain practices, such as rewriting a memory location whenever an error is detected, or using "memory scrubbing" techniques, can significantly reduce the probability of a double soft error occurrence. Memory scrubbing is when the system, during low usage, actually accesses memory solely for the purpose of identifying and correcting single soft errors. This is an important technique if there are segments of the memory that are not always being accessed so that soft error occurrences would not be quickly found.

The occurrence of a double error comprising one soft and one hard must now be considered. This type of error has a higher probability than two soft errors. The hard error may be due to a catastrophic chip failure, and a subsequent soft error will create two errors. This can be a source of concern since most error correction chips cannot handle double errors of this type. Therefore, most systems will "crash" when a catastrophic chip failure is coupled with a soft error in the same memory address.

The DP8400 has been designed to handle just such an occurrence. It can correct any double bit error, as long as at least one of the errors is a hard error. The DP8400 does this without the need for extra hardware required for the basic double bit detect/single bit correct system implementation. This method is called the double complement correct technique and is demonstrated in Figure 12 using a 4-bit data word for simplicity. In this example, a single hard error is located in the most significant bit of a particular memory location and a soft error occurs at the next bit. The position of the errors is not important since the errors may be distributed in either the data or check bit field or both. First, the data word and corresponding check bits are written to this memory location. When a later read of this location occurs, step A, two errors are directly reported by the DP8400 error flags. The system detects this, disables memory, and places the DP8400 in the complement write mode. This causes the previously read data and check bits to be complemented in the DP8400 and written back to the same memory address, step B, writing over the previous soft error. Obviously this does not modify the cell where the hard error exists. The system then reads from the same address again, but this time it places the DP8400 in the complement read mode, step C. The DP8400 again complements the memory data and check bits and generates new check bits based on the new data word. At this point, the chip detects a single bit error in the bit position where the soft error occurred, and using the conventional single error correction procedure, returns corrected data to the system, step D.

In the second read, the complement read, the hard error repeats since this bit location again receives a bit which is complemented with respect to itself. But the soft error has

been overwritten and does not repeat. Effectively, the memory has complemented the hard bit error position twice and the soft bit error position only once, while the DP8400 complements both positions twice. Therefore, after the second read, there is only one error left, the soft error. Since this is now a single error it can be directly corrected.

After the complement correct cycle, the memory must be rewritten with the corrected data since the address now contains data that is complemented. Full error reporting is available from the DP8400 after the second read, the complement read, of memory. This is shown in Table VI.

This method is a very effective tool to avoid system crash due to memory chip failure, and can do much to reduce unscheduled field service calls. The only time the system will

see a double error that is not directly correctable is when a double soft error occurs. The probability of this is very low if the previously discussed techniques are used. The extra time taken to do an additional read and write of memory is insignificant when the alternative is a system that has a catastrophic failure that requires immediate field service. Using this technique, software may be provided in the system to warn the operator that the system is in a degraded operational mode and that field service should occur shortly. In the meantime, the system will continue to operate properly. The key to the effectiveness of the DP8400 in this application is its three error flags which allow complete error reporting—including a unique double error indication.

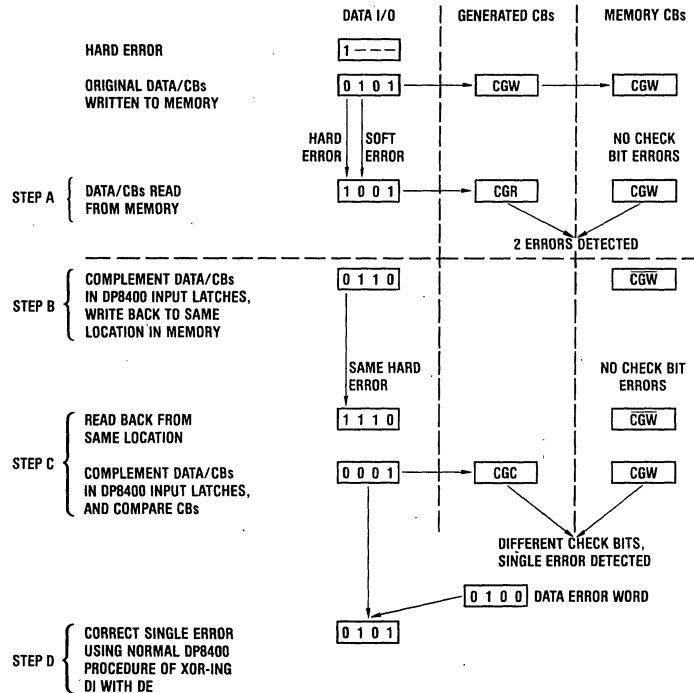


FIGURE 12. Double Error Correct Complement Hard Error Method—1 Hard Error and 1 Soft Error in Data Bits

TABLE VI. DP8400 ERROR FLAGS AFTER A COMPLEMENT READ

AE	E1	E0	Error Type
0	0	0	Two hard errors
1	1	0	One hard error, one soft check bit error
1	1	1	One hard error, one soft data bit error
1	0	0	Two soft errors, not corrected

MICROPROCESSOR INTERFACE CIRCUITS

The major 8-bit and 16-bit microprocessors have different control signal timing. There are also a number of speed options. The DP8400 family was designed, not for a specific microprocessor, but rather, significant control flexibility has been provided on both the DP8409 and the DP8400 for easy interface to any microprocessor. However, a certain amount of "glue" is necessary to interface to these LSI circuits, usually in the form of a number of MSI/SSI logic circuits. Not only can this be costly in board space utilization, but it is usually the one place where the most design related problems occur in system development.

Figures 13 and 14 show the DP8400 family solution to this problem—the DP84300 series of microprocessor interface circuits. Figure 13 shows how the DP84300 refresh timer and the DP843X2 microprocessor interface circuit connect to the DP8409 and various microprocessors. Figure 14 shows the DP8409 and the DP8400 together in a microprocessor-based memory system using DRAMs, with double bit error detect and single bit error correct capability. In addition, it shows that with the simple addition of some standard data buffers, how the system can implement byte writing to the DRAM array.

This system structure requires the insertion of few or no wait states during a memory access cycle, thus maximizing throughput. The DP84300 circuits have been designed to work with the DP8409 to control refreshing so that system throughput is affected only when absolutely necessary. First, in any refresh clock period of 16 μ s, hidden refreshing is given maximum opportunity. This can be helped with the optional DP84300 refresh interval generator which offers maximum high-to-low ratioing of RFCK. Second, when a hidden refresh does not occur in a particular RFCK cycle, a forced refresh may still not affect a slow access cycle. The worst-case is when an access is pending during a forced refresh, in which case a three wait state delay is usually the maximum penalty.

Usually two DP84300 type chips would be required to interface between any microprocessor and the DP8400/DP8409 combined system. These chips would handle the read/write control as well as error detection and correction control. Table VII shows the individual DP84300 circuits that would be used in systems with no error correction, thus requiring only the DP8409 DRAM controller.

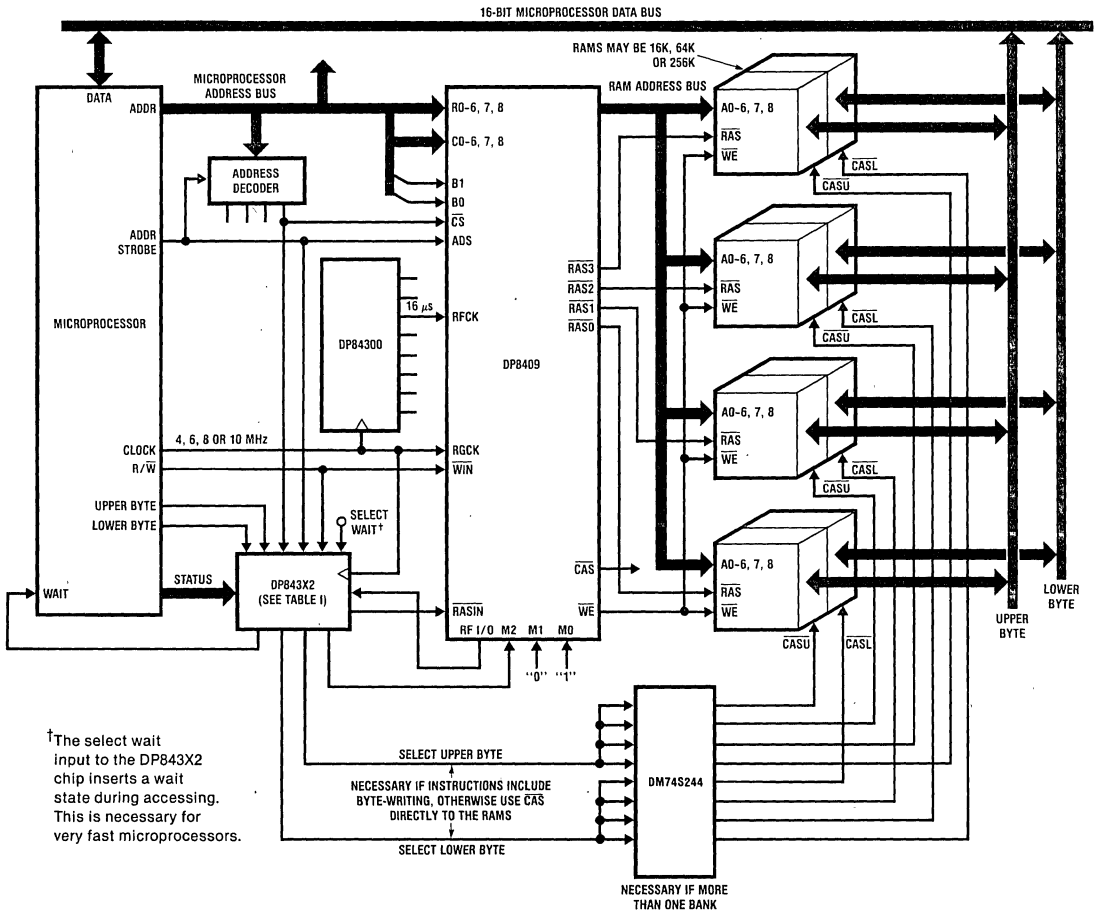


FIGURE 13. Connecting the DP8409 Between 16-Bit Microprocessor and Memory

The DP8400 DRAM interface family provides complete solutions to memory support. This begins with the LSI functions such as the DP8400 expandable error checker/corrector and the DP8409 DRAM controller/driver. It continues with the DP84240 and the DP84244 high performance buffer/drivers. Finally, it concludes with easy interface to popular microprocessors with the use of the DP84300 series. It is the first family of DRAM support cir-

cuits designed for universal applications with multiple microprocessors.

Data sheets and more detailed application information are available for all the members of the DP8400 family. Contact your local National Semiconductor representative or National Semiconductor directly.

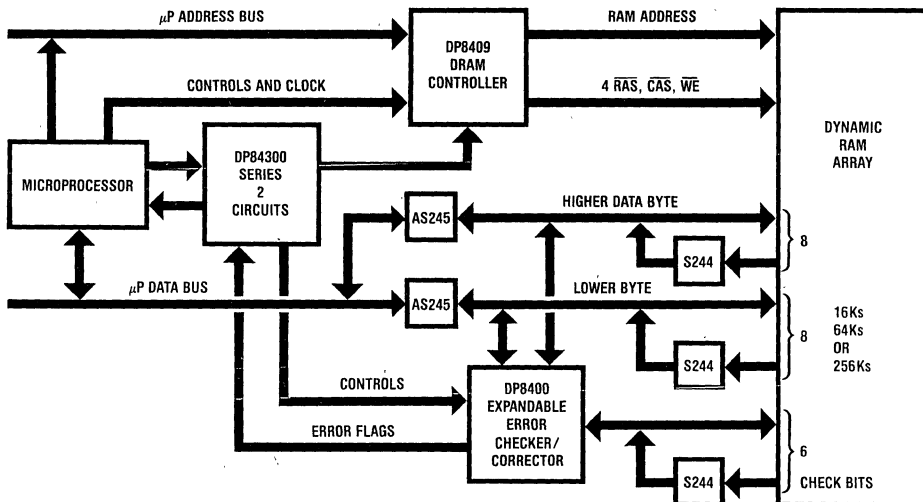


FIGURE 14. Flexible application of the DP8409 and DP8400. This figure shows an application with a 16-bit microprocessor.

TABLE VII. THE DP84300 SERIES OF INTERFACE CIRCUITS FOR VARIOUS 16-BIT MICROPROCESSORS

16-Bit Microprocessor	System Using Only DP8409
National 16032	DP84312
Motorola 68000	DP84322
Intel 8086/8	DP84332
Zilog 8000	(2) 74S64 (1) 74S04

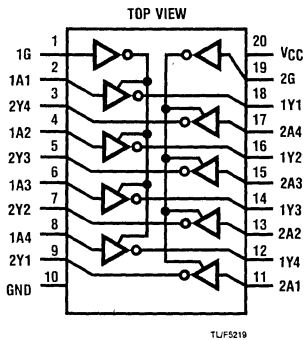
DP84240/DP84244 Octal TRI-STATE® MOS Drivers
General Description

The DP84240 and DP84244 are octal TRI-STATE drivers which are designed for heavy capacitive load applications such as fast data buffers or as memory address drivers. The DP84240 is an inverting driver which is pin-compatible with both the 74S240 and AM2965. The DP84244 is a non-inverting driver which is pin-compatible with the 74S244 and AM2966. These parts are fabricated using an oxide isolation process, for much faster speeds, and are designed for load capacitances of 250pF or greater.

Features

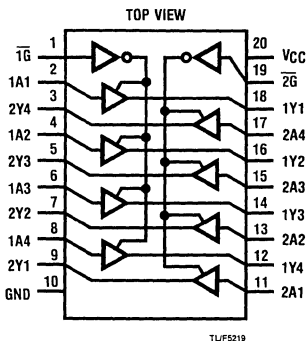
- t_{pd} specified with 250 pF and 500 pF loads
- Output specified from 0.8V to 2.7V
- Designed for symmetric rise and fall times at 500 pF
- Outputs glitch free at power up and power down
- PNP inputs reduce DC loading on bus lines
- Low static and dynamic input capacitance
- Low skew times between edges and pins
- AC parameters specified with all outputs switching simultaneously

TRI-STATE® is a registered trademark of National Semiconductor Corporation

Connection Diagrams
Truth Tables
DP84240


Inputs		Outputs
\overline{G}	A	Y
H	X	Z
L	L	H
L	H	L

H = High Level
L = Low Level
X = Don't Care
Z = High Impedance

DP84244


Inputs		Outputs
\overline{G}	A	Y
H	X	Z
L	L	L
L	H	H

Order Number DP84240J, DP84244J,
DP84240N or DP84244N
See NS Package J20A or N20A

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Logical "1" Input Voltage	7.0V
Logical "0" Input Voltage	-1.5V
Storage Temperature Range	-65°C to +150°C
Maximum Power Dissipation* at 25°C	
Cavity package	1667mW
Molded Package	1832mW
Lead Temperature (soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
V_{CC} Supply Voltage	4.5	5.5	V
T_A Ambient Temperature	0	+70	°C

*Derate cavity package 11.1mW/°C above 25°C; derate molded package 14.7mW/°C above 25°C.

Electrical Characteristics $V_{CC} = 5V \pm 10\%$, $0 \leq T_A \leq 70^\circ C$. See Notes 2 and 3.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$V_{IN(1)}$	Logical "1" Input Voltage		2.0			V
$V_{IN(0)}$	Logical "0" Input Voltage				0.8	V
$I_{IN(1)}$	Logical "1" Input Current	$V_{IN} = 2.7V$		0.1	20	μA
		$V_{IN} = 7.0V$			100	μA
$I_{IN(0)}$	Logical "0" Input Current	$0 \leq V_{IN} \leq 0.4V$		-50	-200	μA
V_{CLAMP}	Input Clamp Voltage	$I_{IN} = -18mA$		-1	-1.2	V
V_{OH}	Logical "1" Output Voltage	$I_{OH} = -100\mu A$ $I_{OH} = -1mA$	$V_{CC} - 1.15$	4.3		V
			$V_{CC} - 1.5$	3.9		
V_{OL}	Logical "0" Output Voltage	$I_{OL} = 10\mu A$ $I_{OL} = 12mA$		0.2	0.4	V
				0.3	0.5	
I_{1D}	Logical "1" Drive Current	$V_{OUT} = 1.5V$	-75	-250		mA
I_{0D}	Logical "0" Drive Current	$V_{OUT} = 1.5V$	+100	+150		mA
Hi-Z	TRI-STATE Output Current	$0.4V \leq V_{OUT} \leq 2.7V$	-100		+100	μA
I_{CC}	Supply Current DP84240	All Outputs Open All Outputs High All Outputs Low All Outputs Hi-Z		16 74 80	50 125 125	mA
	DP84244	All Outputs High All Outputs Low All Outputs Hi-Z		40 100 115	75 130 150	

Switching Characteristics

$V_{CC} = 5V \pm 10\%$, $0 \leq T_A \leq 70^\circ C$, all outputs loaded with specified load capacitance and all eight outputs switching simultaneously. (See Note 3.)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{PLH}	Propagation Delay from LOW-to-HIGH Output	Figures 1 & 3 $C_L = 250 \text{ pF}$ $C_L = 500 \text{ pF}$	9	16	27	ns
t_{PHL}	Propagation Delay from HIGH-to-LOW Output		9	16	25	
			12	20	31	ns
t_{PLZ}	Output Disable Time from LOW	Figures 2 & 4, $S = 1$, $C_L = 50 \text{ pF}$		11	24	ns
t_{PHZ}	Output Disable Time from HIGH	Figures 2 & 4, $S = 2$, $C_L = 50 \text{ pF}$		12	24	ns
t_{PZL}	Output Enable Time to LOW	Figures 2 & 4, $S = 1$, $C_L = 500 \text{ pF}$		30	45	ns
t_{PZH}	Output Enable Time to HIGH	Figures 2 & 4, $S = 2$, $C_L = 500 \text{ pF}$		23	35	ns
t_{SKEW}	Output-to-Output Skew See Note 4.	Figures 1 & 3 $C_L = 500 \text{ pF}$		3		ns

Capacitance

$T_A = 25^\circ C$, $f = 1 \text{ MHz}$, $V_{CC} = 5V \pm 10\%$. See Note 3.

Parameter	Conditions	Typ	Units
C_{IN}	All other inputs tied low	6	pF
C_{OUT}	Output in TRI-STATE	20	pF

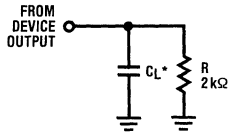
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All currents into device pins shown as positive; all currents out of device pins shown as negative; all voltages referenced to ground unless otherwise noted. All values shown as max. or min. are on an absolute value basis.

Note 3: Typical characteristics are taken at $V_{CC} = 5.0V$ and $T_A = 25^\circ C$.

Note 4: The output-to-output skew is primarily a function of the number of outputs switching and the capacitive loading on those outputs. See Figures 5 and 6 for the switching time variations.

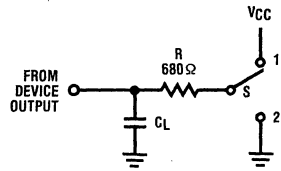
Switching Test Circuits



*C_L INCLUDES PROBE AND JIG CAPACITANCES

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FIGURE 1. Capacitive Load Switching

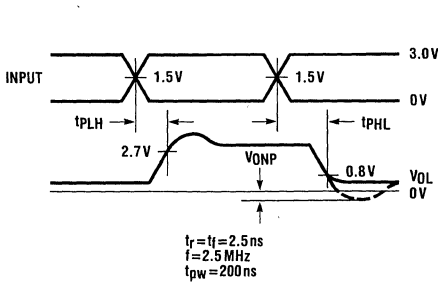


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FIGURE 2. Three-State Enable/Disable

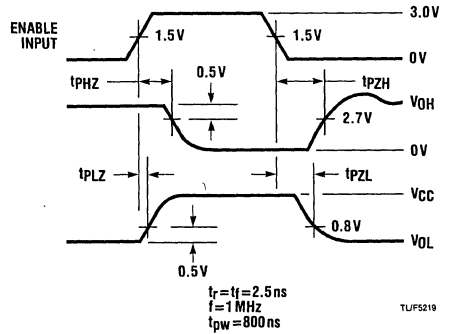
Typical Switching Characteristics

Voltage Waveforms



TUF5219

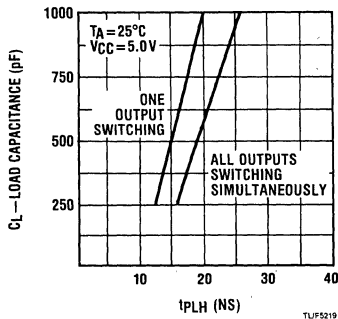
FIGURE 3. Output Drive Levels



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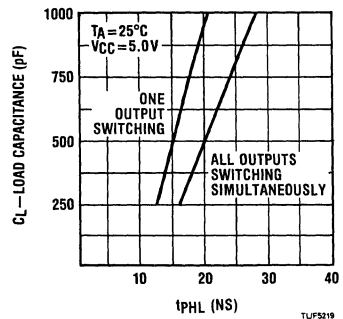
FIGURE 4. Three-State Control Levels

Typical Performance Curves



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FIGURE 5. t_{PLH} Measured to 2.7V on Output vs. C_L



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FIGURE 6. t_{PLH} Measured to 0.8V on Output vs. C_L

Typical Performance Curves (Continued).

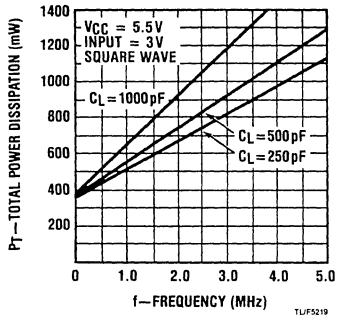


FIGURE 7. Typical Power Dissipation for DP84240 at $V_{CC} = 5.5V$ (All 8 drivers switching simultaneously)

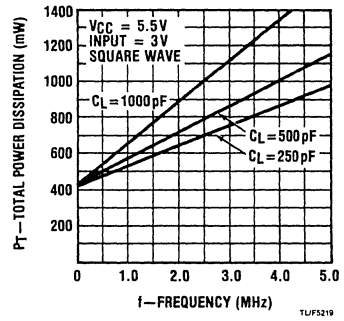
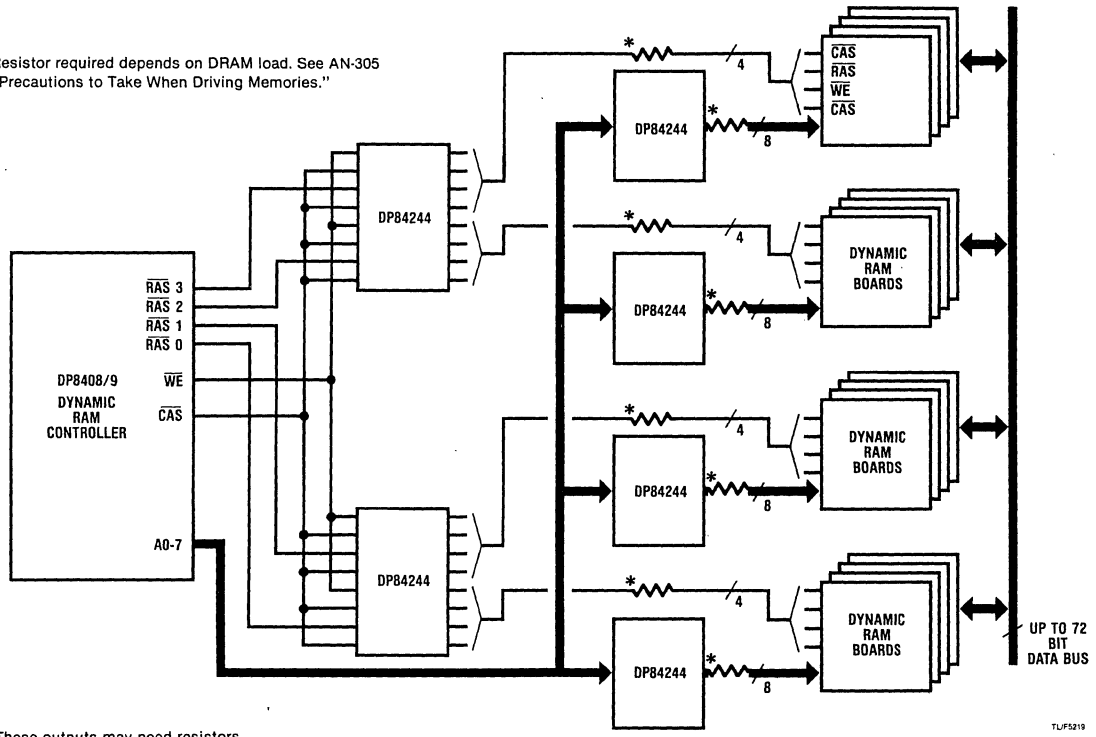


FIGURE 8. Typical Power Dissipation for DP84244 at $V_{CC} = 5.5V$ (All 8 drivers switching simultaneously)

Typical Application

*Resistor required depends on DRAM load. See AN-305 "Precautions to Take When Driving Memories."



*These outputs may need resistors. See App. Note "Precautions to Take When Driving Memories."

DP84244 used as a buffer in a large memory array (greater than 88 dynamic RAMs)

A family of single-chip dynamic RAM controllers provides the access-timing and refreshing capability for any chip made, or projected.

Single-chip controllers cover all RAMs from 16-k to 256-k

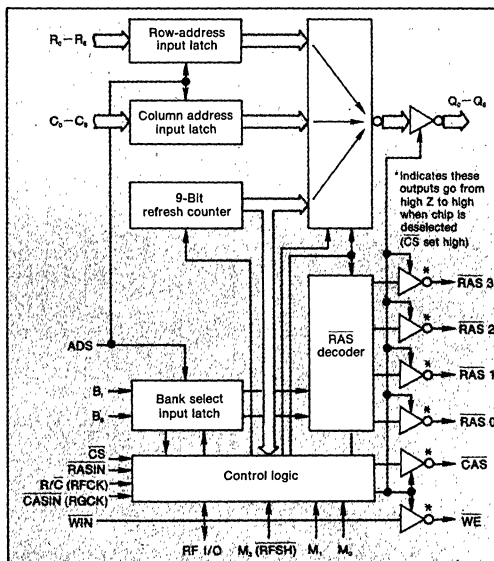
While the high performance and low cost of MOS dynamic RAMs make them the most widely used digital semiconductor devices, operating them is more difficult than most other memory chips. Demands are growing for both the automatic sequencing of RAM-access timing and the automatic control of refreshing. National Semiconductor's response is the DP8400 family of memory-interface circuits. The first two members, the DP8408 and the DP8409, are powerful single-chip dynamic-RAM controllers housed in 48-pin dual-in-line packages and, more important, designed to drive the entire range of dynamic RAMs.

The DP8408's eight address outputs drive all current 16-k and 64-k dynamic RAMs. The DP8409, with nine address outputs, not only handles the same RAMs as the 8408, but can control the coming generation of 256-k memory chips. Both devices are pin-compatible, which means a system designed with the DP8408 to control 64-k chips can be directly upgraded to the DP8409 when 256-k RAMs appear on the market. Another benefit for designers is alternate-sourcing—the first DP8400 devices are available from Monolithic Memories (Sunnyvale, CA).

The DP8408, a subset of the DP8409, fits into applications that do not require automatic refreshing. But it does have automatic access modes. The DP8409 is designed for any type of dynamic RAM system, from small microprocessor-based systems to large memory boards. An automatic-accessing mode makes it desirable in mainframes, since it reduces skew time to that of just one chip, while offering tracking of the RAM input controls. This faster accessing permits the use of slower RAMs. With 64-k RAMs, for example, the cost

savings between 200-ns and 150-ns devices is significant when large quantities are involved.

Microprocessor users will prefer the DP8409 to other controllers because a single chip performs all the basic automatic access sequencing and automatic refreshing control. (If desired, external refreshing can be used with either controller.) Fast automatic accessing eliminates the need for the wait states that are normally required in faster microprocessors. Automatic refreshing eliminates complicated refresh-arbitration control circuitry while offering a



1. With a 9-bit output bus suitable for interfacing with the largest dynamic RAMs (256 k), National Semiconductor's DP8409 RAM controller drives every RAM available. Features include automatic accessing, automatic refreshing, and high-impedance outputs when not selected. An 8-bit version, the DP8408, operates with RAMs up to 64 kbits, and is used in applications that do not require automatic refreshing.

Mike Evans, Applications Manager, Logic Group
Charles Carlinali, Design Manager, Interface Circuits

hidden refresh feature to increase the system throughput. The DP8409 offers full control, including byte writing, of the 68000, 8086, and Z8000 microprocessors, and National Semiconductor's new 16032 16-bit microprocessor.

Controlling a dynamic RAM is no simple task (see "Dynamic RAM Operation—from RAS to CAS"). Three timing delays are required for an access, and refreshing must be performed continually. With the arrival of powerful 16-bit processors and their large, direct memories, a single-chip controller becomes necessary for efficient system design. Propagation timing delays through the controller must be in the tens of nanoseconds to minimize total access time. Moreover, to eliminate the propagation delays caused by additional memory drivers, a controller should be capable of directly driving a large number of RAMs. The controller must also reduce component cost and conserve PC-board area.

To fulfill these requirements, the DP8408 and 8409 are fabricated in bipolar technology rather than MOS. LSI capability exists in bipolar technology, and bipolar dynamic-RAM controllers are already available. Two such controllers, Intel's 8202 and AMD's 2964 (AMZ8164), represented early attempts to bring timing delays under system control.

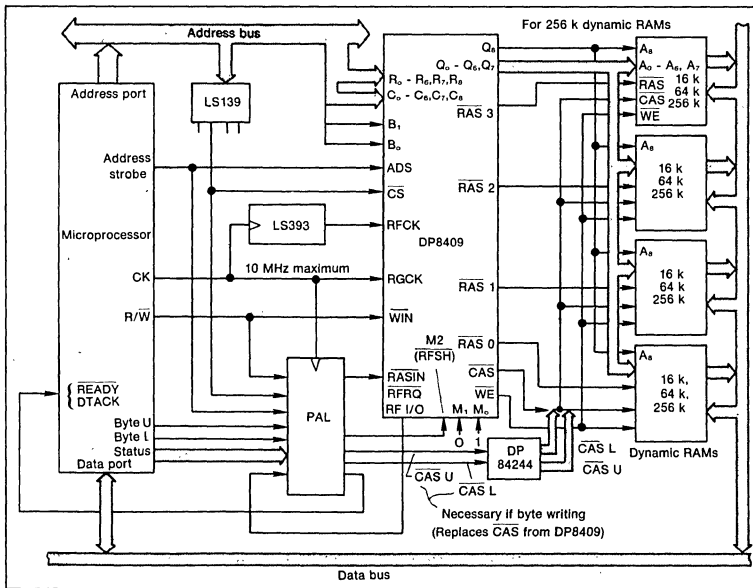
In the Intel device, the clock is independent of the

access-request signal, causing excessive synchronizing delays before the appearance of the output signals. This leads to long system access times, and for most 16-bit microprocessors requires the insertion of wait states. The AMD controller is an address multiplexer with an on-board refresh counter and bank selection for up to four banks of RAMs. While this device drives a small number of RAMs, AMD offers octal memory drivers that can be placed between the 2964 and the RAMs. Delays become progressively longer as timing signals proceed through the delay timer, the 2964, and the additional drivers. And external components are needed to initiate timing delays. Quite simply, the DP8408 and DP8409 go well beyond the access-time and functional capabilities of the 8202 and 2964.

On board the RAM controllers

A functional block diagram of the DP8409 is shown in Fig. 1. The DP8408 is similar, except for its 8-bit-wide multiplexed address-bus and the fact that its R/C and CASIN inputs do not provide dual functions as RFCK and RGCK inputs, as they do in the 8409.

The multiplexed address outputs of both controllers can be selected from the row or column input latches, or from the refresh counter. A high level on input signal ADS enables input row-addresses, R₀



2. The interface of the DP8409 RAM controller to a 16-bit microprocessor looks ahead to the day when 256-kbit dynamic RAMs are available. By designing-in the controller now, no modifications to printed-circuit boards will be necessary when 256-k devices are developed. Simply exchanging controller chips will allow the memory-control capability of a microprocessor to increase by four times.

through R_0 , input column-addresses C_0 through C_8 , and bank-select inputs B_0 and B_1 into their respective input latches. ADS also latches these signals on its low-going edge. In a normal RAM access, B_0 and B_1 are decoded to determine which bank is selected. By enabling one of the four RAS outputs (when RASIN goes low), the contents of the row-address latch are strobed into the selected RAMs.

Now the control logic causes the row addresses to be replaced with the column addresses, and CAS goes low as determined by the control logic. This causes the contents of the column-address latch to be strobed into the selected RAMs.

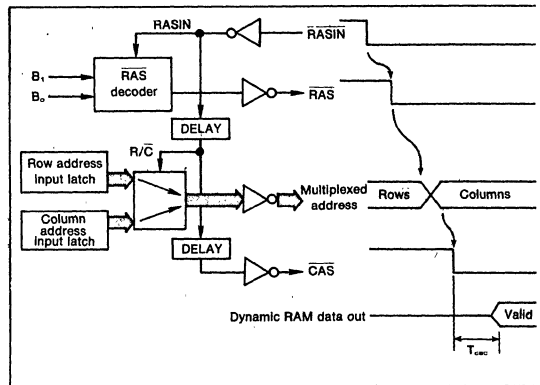
On a write cycle, \overline{WE} must be low as \overline{CAS} goes low; on a read cycle, \overline{WE} must be high. For a read-modify-write cycle, \overline{WE} must go low some time after \overline{CAS} —this is specified in RAM data sheets. To simplify control, \overline{WE} follows \overline{WIN} unconditionally 20 ns later, typically. Three mode pins— M_0 , M_1 , and M_2 (M_2 is refresh mode)—offer externally selected operating modes. For example, mode 5—automatic access—identified by code 101, can be changed to mode 1—forced refresh—identified by code 100, when M_2 is driven low. These modes include automatic and external control of accesses, and various refreshing modes.

Input pin \overline{CS} selects or deselects the controller to allow for multiaddressing of memory. For accesses, \overline{CS} is normally low, but to access a second DP8409 sharing the same memory, \overline{CS} of the first 8409 must go high. This puts the three-state address outputs in a high-impedance high-state through an external 5-k Ω pull-up resistor, and sets the control signals to a high impedance to prevent them from drifting low; a low level can result in a false access. Switching between chips takes about 30 ns, providing fast multiaddressing. Refreshing must be performed using only one chip. As \overline{CS} goes high in mode 5, deselection is overridden and, provided R \overline{FCK} is already high, hidden refreshing can occur.

Input/output pin RF I/O can be used to clear the refresh counter when it has been set low by an external open-collector gate. It also sends out an end-of-count signal—a low level—when the refresh counter has filled (counts are selectable to 127, 255, or 511). This is a useful feature for burst refreshing. In the automatic-refresh mode, RF I/O becomes the signal Refresh Request.

No problems with capacitive loads

One important asset of the DP8408 and 8409 is their ability to drive high-capacitance loads. RAM inputs are generally specified as having a maximum input capacitance of 10 pF/pin, but in large RAM systems, the worst-case input capacitance is usually on the order of 2.5 pF per input. However, one or two devices



3. The DP8408/8409's automatic-accessing capability uses on-chip delay paths to provide faster access while saving on external delay-timing circuitry. On-chip Schottky inverters track extremely well with temperature and voltage, keeping access-times stable.

in a system can go up to 10 pF, especially at high temperature. On the other hand, RAM input currents carry specifications of around 10 μ A maximum, but actual input currents seldom exceed 3 μ A per input in large systems. Of the two parameters—capacitance and input current—high capacitance always causes more system problems.

In addition to a RAM's input capacitance, designers must consider the capacitance of the PC-board traces. The value of capacitance depends on trace length, nearness to other traces, board thickness, etc. Generally, this amounts to about 3.2 pF per input, giving a total worst-case input capacitance of 5.7 pF/input.

The output stages of the DP8408/8409 can drive up to 88 RAMs, or 500 pF of capacitive loading. Looking at it another way, the controllers can drive four banks each of 16-data bits plus 6 associated check bits for error correction; two banks of 32 data bits with 7 check bits; one bank of 64 data bits with 8 check bits; or any smaller combination. Output rise and fall times are proportional to the capacitive loading, and more than 500 pF increases transition time. Similarly, less than 500 pF decreases propagation delays.

The output-driver stages of the DP8409/8409 are matched. Each stage has symmetrical high and low drive capability, which requires that the high and low on-resistances be the same. High output currents are needed to quickly charge or discharge the effective RAM load capacitance on each output. In most applications, a series damping resistor is required between each output and the RAM to minimize undershoot. Undershoot occurs at RAM inputs having both inductive board traces and high capacitive loads on high-to-low transitions.

The value of the series damping resistor depends heavily on the board layout. Address lines usually use a value different from control lines, but both are functions of layout and input loading. The resistor is almost tuned to a specific board since too high a value yields an excessively slow edge, while too low a value does not remove the undershoot. In any case, damping-resistor values vary from 15 to 100 Ω .

Control over all RAMs

The DP8408 and 8409 are designed to control all multiplexed-address dynamic RAMs. The DP8408, with eight multiplexed address outputs and an 8-bit refresh counter, controls 16-k dynamic RAMs (+5 V or three-power-supply types) and both configurations of 64-k RAMs (128 rows by 512 columns or 256 rows by 256 columns). Memory users can specify either of the two 64-k RAM configurations provided the refresh counter on the DP8408 is used. This replaces on-the-RAM refresh counters offered by some RAM manufacturers.

The DP8409's nine address pins and 9-bit refresh counter allow it to control 16-k, 64-k, and 256-k RAMs. Designers can take advantage of the 8409's 256-k capability by building current memory boards using the device. No modifications will be needed when the 256-k RAMs are available. By simply providing for two new input address lines and connecting Q_8 (the ninth multiplexed address output) to A_8 (pin 1) of the RAMs, the memory size can be increased instantly by a factor of four. Figure 2 shows how the connections are made.

Automatic accessing capability is provided by the 8408 and 8409 using on-chip delay paths to generate the correct timing sequence (Fig. 3). These delays are initiated from only one input signal, \overline{RASIN} . This generates all the access-sequencing required by most RAMs. Automatic accessing operates in the following manner: First, \overline{RASIN} is used to generate the selected \overline{RAS} output as decoded from bank-select signals B_1 and B_0 . \overline{RASIN} is also fed to the first series of Schottky inverters to produce the necessary delay before rows can be switched to columns. This guarantees exceeding the row-address hold time (t_{RAH}) of most RAMs. For 64-k RAMs, t_{RAH} varies from 20 to 25 ns, so the minimum specification for the 8408 and 8409, 30 ns, is on the safe side. If the address outputs are driving 500-pF loads, switching from row addresses to valid column addresses takes 10 ns. The second series of inverters set \overline{CAS} low 12 ns (typically) after the columns are valid.

The inverters track with temperature and V_{CC} , as do the output driver stages. Tracking of the output paths holds over the specified temperature and V_{CC} ranges. Since Schottky-logic parameters do not vary significantly with temperature or V_{CC} , the absolute

times are not affected by more than 25% over the 0 to 70°C range. At the end of an access-cycle, \overline{RASIN} goes high and the sequence repeats at a higher speed to terminate the cycle.

An automatic-access mode offers two important advantages: First, there is no need for external timing delay circuitry—this saves cost, memory-board area, and the timing skews that external circuitry introduces. Second, this sequence is much faster than a clocked sequencing approach—that is, the delay from \overline{RASIN} input to \overline{CAS} output is much shorter. Benefits include a faster system access time, the possibility of eliminating a wait state in a microprocessor memory-access cycle, or the ability to choose slower RAMs (a lower-cost solution) without affecting access time. And since both chips need no external memory drivers, the timing skews are confined to just one chip.

If automatic timing is not desired, another mode allows all timing to be under the control of the relevant external control signals. \overline{RASIN} initiates the selected \overline{RAS} output, R/\overline{C} selects either the row or column address, and \overline{CASIN} controls \overline{CAS} .

Refreshing comes in many forms

The DP8408 performs refresh operations only under external control. The microprocessor system decides when a refresh is needed by setting M_2 (REFRESH) low to place the refresh counter contents on the address outputs. Then the system sets \overline{RASIN} low to allow all four \overline{RAS} outputs to low-stroke the refresh address into the rows of all four banks of RAMs. \overline{CAS} is inhibited, preventing a false write, and the RAM data outputs remain in a high-impedance state.

A refresh cycle ends when \overline{RASIN} goes high and the refresh counter increments, ready for the next refresh cycle. Most RAMs require that all 128 rows be refreshed in 2 ms, or 256 rows in 4 ms. This can be accomplished by either guaranteeing a refresh on one row every 16 μ s, or performing a burst refresh of 128 rows at the start of each 2-ms period, until $RF I/O$ indicates end-of-count. Most system designers prefer one refresh every 16 μ s. But this can involve inhibiting normal memory accessing, and requires refresh arbitration.

The end-of-count indication on $RF I/O$ can be set under external system control to either 127 or 255 for burst-refresh applications. Actually, the internal address counter still counts to its maximum value, independent of the end-of-count value—the $RF I/O$ value is a result of counter decode and does not reset the counter. This simplifies the RAM interface since the higher-order address bit-count is ignored by RAMs with 128 rows.

In addition to providing the external-control

refresh mode of the 8408, the 8409 performs hidden refreshing in one of the automatic-access modes. To attain maximum throughput, it is obviously advantageous to perform refreshes without interrupting the system. The DP8409 can do this by monitoring the \overline{CS} input to see if it is high. If \overline{CS} is high, the RAMs are not being accessed. If \overline{CS} is high for one cycle, the 8409 performs a hidden refresh during this cycle, and stops in time for the system to start another access. But if a hidden refresh does not occur

in a specific 16- μ s time slot, a refresh must be forced, possibly by stopping the system.

To perform auto-refreshing, the DP8409 must receive two clock signals: the 16- μ s refresh-period clock, RFCK, and RGCK, the RAS-generator clock; RGCK can be the microprocessor clock. To keep the number of pins at 48, RFCK and RGCK share pins with other signals. In the automatic-access mode (mode 5), neither R/\overline{C} nor \overline{CASIN} are used, so these duplicate as RFCK and RGCK in modes 1 and 5. To stop the

Dynamic RAM operation—from RAS to \overline{CAS}

The operation of a dynamic RAM (see figure) is, in a word, complex: Not only do its multiplexed address inputs require delayed timing signals, but it must be refreshed continually.

During an access to a RAM, the first step requires that a row address be presented to the multiplexed address inputs. As the row-address signal (\overline{RAS}) goes low, the address is latched into the row latch, and decoded to the memory array. There, the outputs from the selected row are presented to the sense amplifiers. Row addresses must be held on the address inputs for a predetermined time— t_{RAIL} , or row-address hold-time—after \overline{RAS} switches low.

At this time, the row address can be replaced by a column-address. When a column address is valid, the column-address strobe (\overline{CAS}) goes low to latch the address into the column latch. Column-addresses are decoded to allow a selected sense amplifier to send data to the output data-latch (during a read cycle). In a write cycle, with the Write Enable signal (\overline{WE}) already low, a low-going \overline{CAS}

signal causes the selected cell to be set to the value at the data input.

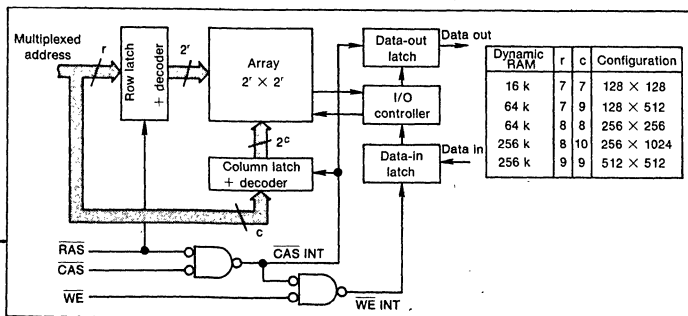
The RAM block diagram shows the chip's operation, including the internal gating of the control signals. One key feature is that \overline{RAS} internally controls \overline{CAS} . Thus, if \overline{RAS} is already low when \overline{CAS} goes low, a normal read or write cycle follows, and the chip consumes its full operating current. On the other hand, if \overline{CAS} goes low while \overline{RAS} is high, \overline{CASINT} is inhibited along with \overline{RAS} , and the RAM consumes only the current required for standby. In this case, the chip is deactivated. Similarly, \overline{WEINT} is controlled by both \overline{RAS} and \overline{CAS} .

This simplifies bank selection by using different \overline{RAS} outputs to select the banks. \overline{CAS} and \overline{WE} can be common to all the RAM-banks, along with the multiplexed addressing. For example, in a four-bank system, only one \overline{RAS} goes low in any access-cycle. This activates all the RAMs in a selected bank, but does not activate RAMs in the other three banks. These latter RAMs remain in the standby mode. The common data bus accesses only the selected

bank, whether reading or writing.

Besides a complex sequencing arrangement, dynamic RAMs must be refreshed to prevent the capacitor in each cell from losing its charge, which represents information. If any row is not accessed for too long a period of time—the refresh period—capacitors will discharge, causing the voltage to drop below the sense-amplifier threshold. Then, when the row is finally accessed, its outputs will appear as all zeros or all ones, depending on which side of the sense amplifier is accessed.

Most RAMs have 2-ms minimum refresh times, but 64-k dynamic RAMs are typically much higher. When accessing a row for refresh, \overline{RAS} is needed for a strobe, but \overline{CAS} is not necessary. The simplest approach to refreshing is to access a refresh counter that increments at the end of each refresh \overline{RAS} . For some RAMs, 128 rows must be refreshed in 2 ms, while others require refreshing 256 rows in 4 ms. With distributed refreshing, one row must be refreshed every 16 μ s for proper operation.



system, the DP8409 gives preference to hidden refreshing using RFCK as a level reference. The 16- μ s cycle commences as RFCK goes high; if CS goes high while RFCK is high, the refresh counter is enabled on the address outputs, overriding the internal three-state signals (Fig. 4a). All four RAS outputs follow RASIN, so to perform a refresh, RASIN must be set low. In smaller systems, RASIN is set low every time a microprocessor performs a read or write cycle. Each time the processor accesses something other than RAM—a peripheral or ROM or another memory segment—a hidden refresh is performed.

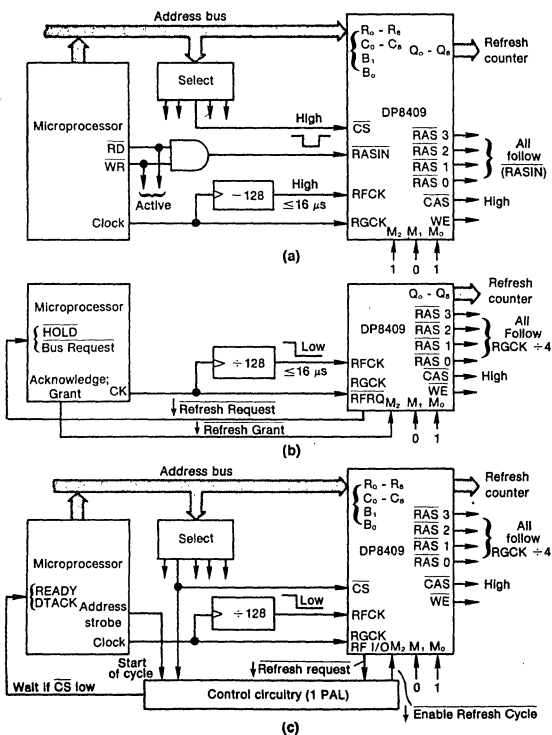
The DP8409 detects that CS is high when the processor accesses another section of the system and places the present state of the refresh counter outputs on the multiplexed address bus to memory. When the Read or Write output of the microprocessor is activated, RASIN follows. This causes all four RAS outputs to low-strobe the refresh

address into the RAMs. When the cycle ends, RASIN ends, forcing the four RAS outputs back to their inactive states. This ends the hidden refresh.

At this time, the refresh counter increments, and another microprocessor cycle can begin immediately. This cycle can be a memory access; therefore, the previous refresh cycle has been completely hidden from the microprocessor. The DP8409 allows only one such hidden refresh cycle to occur within a clock cycle of RFCK to minimize power dissipation.

If a hidden refresh does not occur, the DP8409 must force a refresh before RFCK begins a new cycle on a low-to-high transition. Therefore, as RFCK goes low (and a hidden refresh has not occurred), RF I/O (Refresh Request) goes low requesting that a refresh be performed. When the system acknowledges the request, it sets M₂ (refresh) low, and prevents further accesses to the DP8409. The 8409 then sends out the refresh-counter contents and interrogates RGCK—in most applications, RGCK is 100 to 150 ns. The 8409 waits one full cycle of RGCK before setting all four RAS outputs low. This guarantees that the minimum RAS precharge time of the RAMs is exceeded. Then RF I/O goes high, allowing the system to recognize that holding is about to end. Most microprocessors allow enough time so that as refresh finishes, they are almost ready to begin again. The RAS outputs remain low for the next two clock periods to exceed the minimum t_{RAS} time for refreshing—200 ns is about the right time. When all RAS outputs go high, the refresh counter increments.

A minimum component-count solution to forced refreshing is to connect RF I/O to the Hold or Bus-Request input of a microprocessor, and the Hold Acknowledge or Bus Grant output to M₂ (Fig. 4b). For some microprocessors, it may be preferable to continue operation without going into hold, and with additional circuitry, the approach can be easily implemented as shown in Fig. 4c. Using this technique of forced refreshing, the control circuit monitors the refresh-request output. When this output switches low, the control circuit waits for a new microprocessor cycle to begin. If the next cycle is for the segment of memory controlled by the DP8409, CS and the control circuitry will be set low. The control circuitry issues a Wait signal to the microprocessor, which is removed when refreshing has ended. If CS is set high, the refresh cycle begins and ends without affecting other system cycles. In effect, this is still a hidden refresh. □



4. Automatic refreshing can be performed in three different ways with the DP8409 controller. A hidden refresh (a) occurs while the microprocessor is reading or writing elsewhere in the system. Although undesirable, forced refreshing (b) can be performed by stopping the microprocessor. A better technique for forced refreshing (c) is to insert wait states into the processor timing cycle.

DP8408 Dynamic RAM Controller/Driver

General Description

Dynamic memory system designs, which formerly required several support chips to drive the memory array, can now be implemented with a single IC... the DP8408 Dynamic RAM Controller/Driver. The DP8408 is capable of driving all 16k and 64k Dynamic RAMs (DRAMs). Since the DP8408 is a one-chip solution (including capacitive-load drivers), it minimizes propagation delay skews, the major performance disadvantage of multiple-chip memory drive and control.

The DP8408's 6 modes of operation offer a wide selection of DRAM control capabilities. Memory access may be controlled externally or on-chip automatically; an on-chip refresh counter makes refreshing less complicated.

The DP8408 is a 48-pin DRAM Controller/Driver with 8 multiplexed address outputs and control signals. It consists of two 8-bit address latches, an 8-bit refresh counter, and control logic. All output drivers are capable of driving 500 pF loads with propagation delays of 25 ns. The DP8408 timing parameters are specified driving the typical load capacitance of 88 DRAMs, including trace capacitance.

The DP8408 has 3 mode-control pins: M2, M1, and M0, where M2 is in general REFRESH. These 3 pins select 6 modes of operation. Inputs B1 and B0 in the memory access modes (M2=1), are select inputs which select one of four RAS outputs. During normal access, the 8 address outputs can be selected from the Row Address Latch or the Column Address Latch. During refresh, the 8-bit on-chip refresh counter is enabled onto the address bus and in this mode all RAS outputs are selected, while CAS is inhibited.

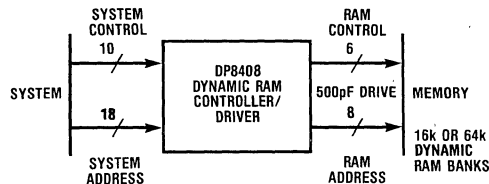
The DP8408 can drive up to 4 banks of DRAMs, with each bank comprised of 16k's, or 64k's. Control signal outputs RAS, CAS, and WE are provided with the same drive capability. Each RAS output drives one bank of DRAMs so that the four RAS outputs are used to select the banks, while CAS, WE, and the multiplexed addresses can be connected to all of the banks of DRAMs. This leaves the non-selected banks in the standby mode (less than one tenth of the operating power) with the data outputs in TRI-STATE®. Only the bank with its associated RAS low will be written to or read from.

Operational Features

- All DRAM drive functions on one chip — minimizes skew on outputs, maximizes AC performance
- On-chip capacitive-load drives (specified to drive up to 88 DRAMs)
- Drives directly all 16k and 64k DRAMs
- Capable of addressing 64k and 256k words
- Propagation delays of 25ns typical at 500pF load
- CAS goes low automatically after column addresses are valid if desired
- Auto Access mode provides RAS, Row to Column, select, then CAS automatically and fast
- WE follows WIN unconditionally—offering READ, WRITE or READ-MODIFY-WRITE cycles
- On-chip 8-bit refresh counter with selectable End-of-Count (127 or 255)
- End-of-Count indicated by RF I/O pin going low at 127 or 255
- Low input on RF I/O resets 8-bit refresh counter
- CAS inhibited during refresh cycle
- Fall-through latches on address inputs controlled by ADS
- TRI-STATE outputs allow multi-controller addressing of memory
- Control output signals go high-impedance logic "1" when disabled for memory sharing
- Power-up: counter reset, control signals high, address outputs TRI-STATE, and End-of-Count set to 127

Mode Features

- 6 modes of operation: 3 access, 1 refresh, and 2 set-up
- 2 externally controlled modes: 1 access (Mode 4) and 1 refresh (Modes 0, 1, 2)
- 2 auto-access modes RAS → R/C → CAS automatic, with $t_{RAH} = 20$ or 30ns minimum (Modes 5, 6)
- Externally controlled All-RAS Access modes for memory initialization (Mode 3)
- End-of-Count value of Refresh Counter set by B1 and B0 (Mode 7)



DP8408 Interface Between System & DRAM Banks

Block Diagram

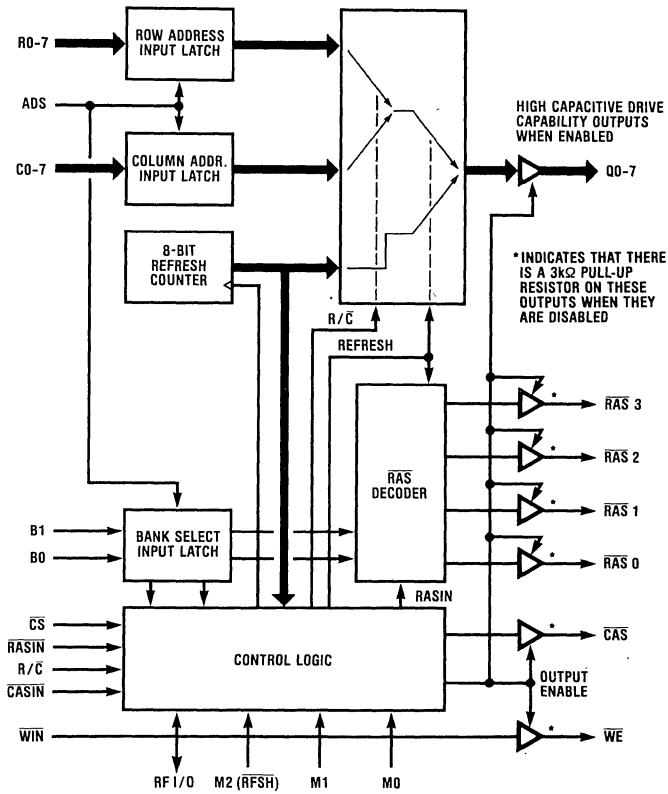


Table 1. DP8408 Mode Select Options

Mode	(RFSH) M2	M1	M0	Mode of Operation	Conditions
0	0	0	0	Externally Controlled Refresh	RF I/O = \overline{EOC}
1	0	0	1		
2	0	1	0		
3	0	1	1	Externally Controlled All- \overline{RAS} Write	All- \overline{RAS} Active
4	1	0	0	Externally Controlled Access	Active \overline{RAS} defined by Table 2
5	1	0	1	Auto Access, Slow t_{RAH}	Active \overline{RAS} defined by Table 2
6	1	1	0	Auto Access, Fast t_{RAH}	Active \overline{RAS} defined by Table 2
7	1	1	1	Set End of Count	See Table 3 for Mode 7

Pin Definitions

V_{CC}, GND, GND — V_{CC} = 5V ± 5%. The three supply pins have been assigned to the center of the package to reduce voltage drops, both DC and AC. There are also two ground pins to reduce the low level noise. The second ground pin is located two pins from V_{CC}, so that decoupling capacitors can be inserted directly next to these pins. It is important to adequately decouple this device, due to the high switching currents that will occur when all 8 address bits change in the same direction simultaneously. A recommended solution would be a 1μF multilayer ceramic capacitor in parallel with a low-voltage tantalum capacitor, both connected as close as possible to pins 36 and 38 to reduce lead inductance. See Figure below.



*Capacitor values should be chosen depending on the particular application.

R0-R7: Row Address Inputs.

C0-C7: Column Address Inputs.

Q0-Q7: Multiplexed Address Outputs — Selected from the Row Address Input Latch, the Column Address Input Latch, or the Refresh Counter.*

RAS_n: Row Address Strobe Input — Enables selected RAS_n output when M2 (RFSH) is high, or all RAS_n outputs when RFSH is low.

R/C: Row/Column Select Input — Selects either the row or column address input latch onto the output bus.

CAS_n: Column Address Strobe Input — Inhibits CAS output when high in Modes 4 and 3. In Mode 6 it can be used to prolong CAS output.

ADS: Address (Latch) Strobe Input — Row Address, Column Address, and Bank Select Latches are fall-through with ADS high; Latches on high-to-low transition.

CS: Chip Select Input — TRI-STATE's the Address Outputs and puts the control signal into a high-impedance logic "1" state when high (except in Mode 0); enables all outputs when low.

M0, M1, M2: Mode Control Inputs — These 3 control pins determine the 6 major modes of operation of the DP8408 as depicted in Table 1.

RF I/O — The I/O pin functions as a Reset Counter Input when set low from an external open-collector gate, or as a flag output. The flag goes active-low when M2 = 0 and the End-of-Count output is at 127 or 255 (see Table 3).

WIN: Write Enable Input.

WE: Write Enable Output — Buffered output from WIN.*

CAS: Column Address Strobe Output — In Modes 5 and 6, CAS goes low following valid column address. In Modes 3 and 4, it transitions low after R/C goes low, or follows CAS_n going low if R/C is already low. CAS is high during refresh.*

RAS 0-3: Row Address Strobe Outputs — Selects a memory bank decoded from B1 and B0 (see Table 2), if RFSH is high. If RFSH is low, all banks are selected.*

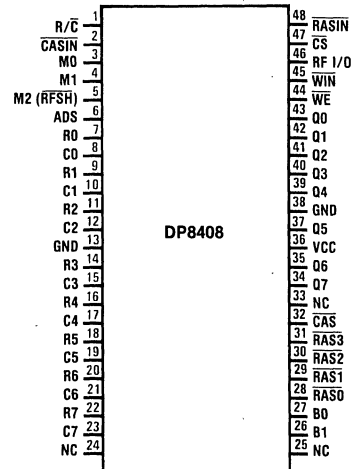
B0, B1: Bank Select Inputs — Strobed by ADS. Decoded to enable one of the RAS outputs when RAS_n goes low. Also used to define End-of-Count in Mode 7 (Table 3).

*These outputs may need damping resistors to prevent overshoot, undershoot. See AN-305 "Precautions to Take When Driving Memories."

Table 2. Memory Bank Decode

Bank Select (Strobed by ADS)		Enabled RAS _n
B1	B0	
0	0	RAS ₀
0	1	RAS ₁
1	0	RAS ₂
1	1	RAS ₃

Connection Diagram



NC=NO CONNECTION

Order Number DP8408N, DP8408N-2
 DP8408N-3, DP8408D, DP8408D-2 or
 DP8408D-3
 See NS Package N48A or D48A

Conditions for all Modes

Input Addressing

The address block consists of a row-address latch, a column-address latch, and a resettable refresh counter. The address latches are fall-through when ADS is high and latch when ADS goes low. If the address bus contains valid addresses until after the valid address time, ADS can be permanently high. Otherwise ADS must go low while the addresses are still valid.

In normal memory access operation, $\overline{\text{RAS}}\text{IN}$ and $\text{R}\overline{\text{C}}$ are initially high. When the address inputs are enabled into the address latches, the row addresses appear on the Q outputs. The address strobe also inputs the bank-select address, (B0 and B1). If $\overline{\text{CS}}$ is low, all outputs are enabled. When $\overline{\text{CS}}$ is transitioned high, the address outputs go TRI-STATE and the control outputs first go high through a low impedance, and then are held by an on-chip high impedance. This allows output paralleling with other DP8408s for multi-addressing. All outputs go active about 50 ns after the chip is selected again. If $\overline{\text{CS}}$ is high, and a refresh cycle begins, all the outputs become active until the end of the refresh cycle.

Drive Capability

The DP8408 has timing parameters that are specified with up to 600 pF loads. In a typical memory system this is equivalent to about 88, 5V-only DRAMs, with trace lengths kept to a minimum. Therefore, the chip can drive four banks each of 16 or 22 bits, or two banks of 32 or 39 bits, or one bank of 64 or 72 bits.

Less loading will slightly reduce the timing parameters, and more loading will increase the timing parameters, according to the graph of Figure 6. The AC performance parameters are specified with the typical load capacitance of 88 DRAMs. This graph can be used to extrapolate the variations expected with other loading.

Because of distributed trace capacitance and inductance and DRAM input capacitance, current spikes can be created, causing overshoots and undershoots at the DRAM inputs that can change the contents of the DRAMs or even destroy them. To remove these spikes, a damping resistor (low inductance, carbon) can be inserted between the DP8408 driver outputs and the DRAMs, as close as possible to the DP8408. The values of the damping resistors may differ between the different control outputs; $\overline{\text{RAS}}$'s $\overline{\text{CAS}}$, Q's and $\overline{\text{WE}}$. The damping resistors should be determined by the first prototypes (not wire-wrapped due to larger distributed capacitance and inductance). The best values for the damping resistors are the critical values giving a critically damped transition on the control outputs. Typical values for the damping resistors will be between 15 Ω and 100 Ω , the lower the loading the higher the value. (For more information, see AN-305 "Precautions to Take When Driving Memories.")

DP8408 Driving any 16k or 64k DRAMs

The DP8408 can drive any 16k or 64k DRAMs. All 16k DRAMs are basically the same configuration, including the newer 5V-only version. Hence, in most applications, different manufacturers' DRAMs are interchangeable (for the same supply-rail chips), and the DP8408 can drive all 16k DRAMs (see Figure 1a).

There are three basic configurations for the 5V-only 64k DRAMs: a 128-row by 512-column array with an on-RAM refresh counter, a 128-row by 512-column array with no on-RAM refresh counter, and a 256-row by 256-column array with no on-RAM refresh counter. The DP8408 can drive all three configurations, and at the same time allows them all to be interchangeable (as shown in Figures 1b and 1c), providing maximum flexibility in the choice of DRAMs. Since the 8-bit on-chip refresh counter can be used as a 7-bit refresh counter for the 128-row configuration, or as an 8-bit refresh counter for the 256-row configuration, the on-RAM refresh counter (if present) is never used. As long as 128 rows are refreshed every 2ms (i.e. 256 rows in 4ms) all DRAM types are correctly refreshed.

When the DP8408 is in a refresh mode, the RF I/O pin indicates that the on-chip refresh counter has reached its end-of-count. This end-of-count is selectable as 127 or 255 to accommodate 16k or 64k DRAMs, respectively. Although the end-of-count may be chosen to be either of these values, the counter is not reset and always counts to 255 before rolling over to zero.

Read, Write, and Read-Modify-Write Cycles

The output signal, $\overline{\text{WE}}$, determines what type of memory access cycle the memory will perform. If $\overline{\text{WE}}$ is kept high while $\overline{\text{CAS}}$ goes low, a read cycle occurs. If $\overline{\text{WE}}$ goes low before $\overline{\text{CAS}}$ goes low, a write cycle occurs and data at DI (DRAM input data) is written into the DRAM as $\overline{\text{CAS}}$ goes low. If $\overline{\text{WE}}$ goes low later than t_{CWD} after $\overline{\text{CAS}}$ goes low, first a read occurs and DO (DRAM output data) becomes valid; then data DI is written into the same address in the DRAM when $\overline{\text{WE}}$ goes low. In this read-modify-write case, DI and DO cannot be linked together. The type of cycle is therefore controlled by $\overline{\text{WE}}$, which follows $\overline{\text{WIN}}$.

Power-Up Initialize

When V_{CC} is first applied to the DP8408, an initialize pulse clears the refresh counter, the internal control flip-flops, and sets the End-of-Count of the refresh counter to 127 (which may be changed via Mode 7). As V_{CC} increases to about 2.3 volts, it holds the output control signals at a level of one Schottky diode-drop below V_{CC} , and the output address to TRI-STATE. As V_{CC} increases above 2.3 volts, control of these outputs is granted to the system.

DP8408 Driving any 16k or 64k Dynamic RAMs

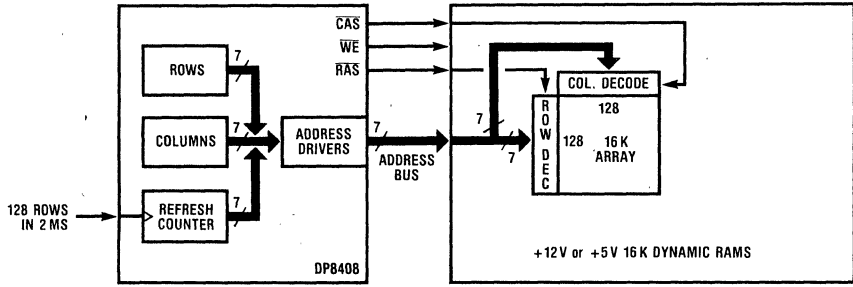


FIGURE 1a. DP8408 with any 16k DRAMS

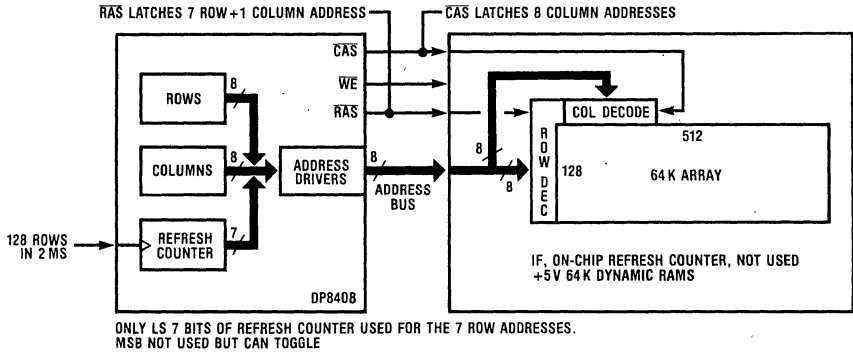


FIGURE 1b. DP8408 with 128 Row x 512 Column 64k DRAM

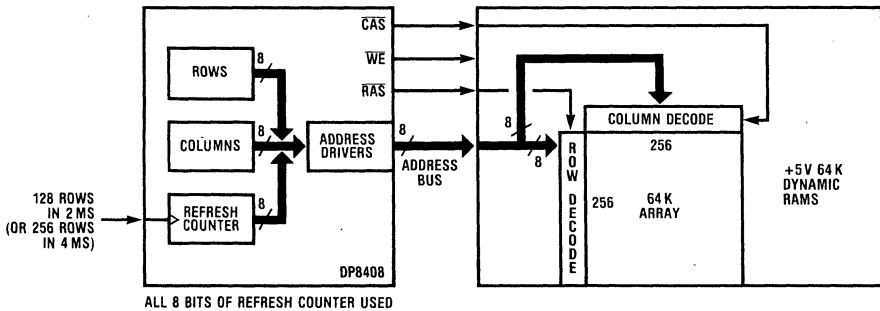


FIGURE 1c. DP8408 with 256 x 256 Column 64k DRAM

DP8408 Functional Mode Descriptions

Note: All delay parameters stated in text refer to the DP8408. Substitute the respective delay numbers for the DP8408-2 or DP8408-3 when using these devices.

Modes 0,1,2 — Externally Controlled Refresh

In this mode, the input address latches are disabled from the address outputs and the refresh counter is enabled. When \overline{RAS} occurs, the enabled row in the DRAM is refreshed. In the Externally Controlled Refresh mode, all \overline{RAS} outputs are enabled following \overline{RASIN} , and \overline{CAS} is inhibited. This refreshes the same row in all four banks. The refresh counter increments when either \overline{RASIN} or \overline{RFSH} goes low-to-high after a refresh. $\overline{RF I/O}$ goes low when the count is 127 or 255, as set by End-of-Count (see Table 3), with \overline{RASIN} and \overline{RFSH} low. To reset the counter to all zeroes, $\overline{RF I/O}$ is set low through an external open-collector driver.

During refresh, \overline{RASIN} and \overline{RFSH} must be skewed transitioning low such that the refresh address is valid on the address outputs of the controller before the \overline{RAS} outputs go low. The amount of time that \overline{RFSH} should

go low before \overline{RASIN} does depends on the capacitive loading of the address and \overline{RAS} lines. For the load specified in the switching characteristics of this data sheet, 10ns is sufficient. Refer to Figure 2.

To perform externally controlled burst refresh, \overline{RASIN} is toggled while \overline{RFSH} is held low. The refresh counter increments with \overline{RASIN} going low to high, so that the DRAM rows are refreshed in succession by \overline{RASIN} going high to low.

Mode 3 — Externally Controlled All-RAS Write

This mode is useful at system initialization. The memory address is provided by the processor, which also performs the incrementing. All four \overline{RAS} outputs follow \overline{RASIN} (supplied by the processor), strobing the row address into the DRAMs. $\overline{R/C}$ can now go low, while \overline{CASIN} may be used to control \overline{CAS} (as in the Externally Controlled Access mode), so that \overline{CAS} strobes the column address contents into the DRAMs. At this time \overline{WE} should be low, causing the data to be written into all four banks of DRAMs. At the end of the write cycle, the input address is incremented and latched by the DP8408 for the next write cycle.

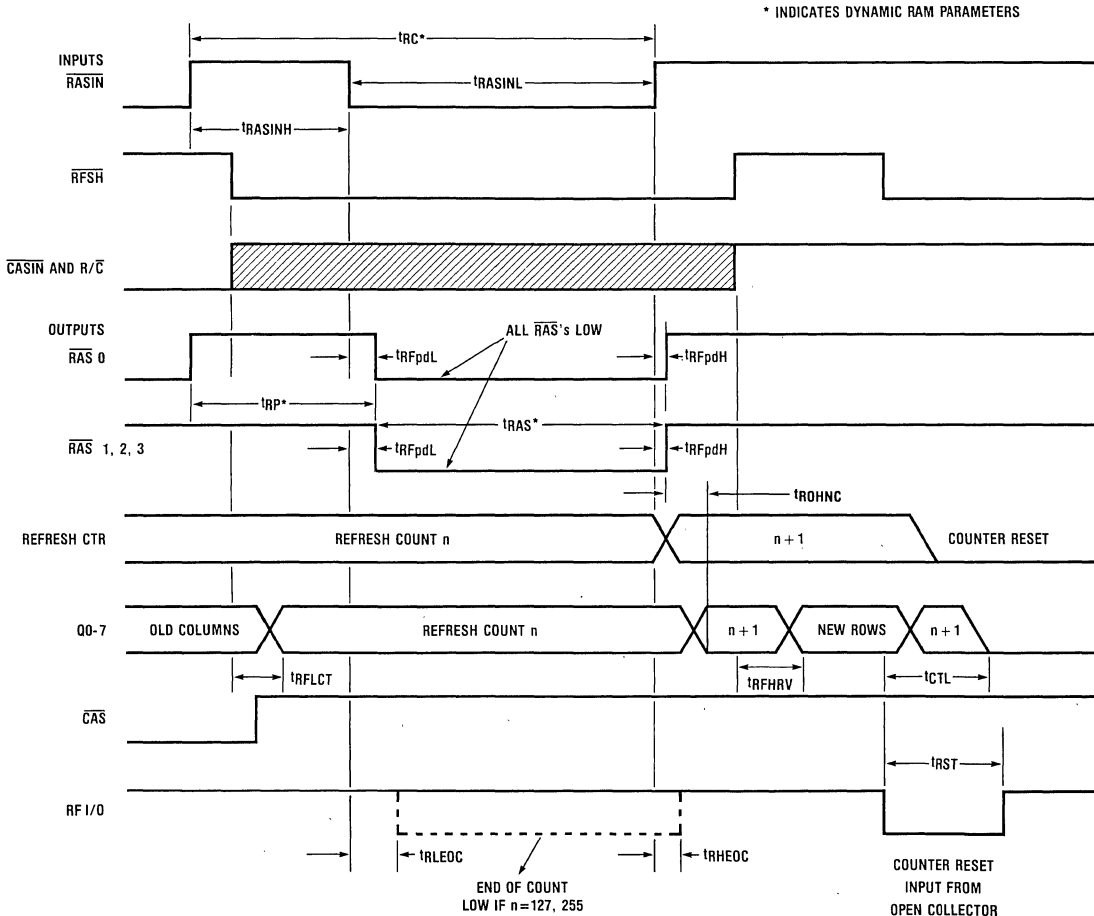


FIGURE 2. External Control Refresh Cycle (MODES 0,1,2)

Mode 4 — Externally Controlled Access

This mode facilitates externally controlling all access-timing parameters associated with the DRAMs. The application of modes 0 and 4 are shown in Figure 3.

Output Address Selection

Refer to Figure 4a. With M2 (\overline{RFSH}) and R/\overline{C} high, the row address latch contents are transferred to the multiplexed address bus output Q0-Q7, provided \overline{CS} is set low. The column address latch contents are output after R/\overline{C} goes low. \overline{RASIN} can go low after the row addresses have been set up on Q0-Q7. This selects one of the \overline{RAS} outputs, strobing the row address on the Q outputs into the desired bank of memory. After the row-address hold-time of the DRAMs, R/\overline{C} can go low so that about 40ns later column addresses appear on the Q outputs.

Automatic \overline{CAS} Generation

In a normal memory access cycle \overline{CAS} can be derived from inputs \overline{CASIN} or R/\overline{C} . If \overline{CASIN} is high, then R/\overline{C}

going low switches the address output drivers from rows to columns. \overline{CASIN} then going low causes \overline{CAS} to go low approximately 40 ns later, allowing \overline{CAS} to occur at a predictable time (see Figure 4b). If \overline{CASIN} is low when R/\overline{C} goes low, \overline{CAS} will be automatically generated, following the row to column transition by about 20 ns (see Figure 4a). Most DRAMs have a column address set-up time before \overline{CAS} (t_{ASC}) of 0 ns or -10 ns. In other words, a t_{ASC} greater than 0 ns is safe. This feature reduces timing-skew problems, thereby improving access time of the system.

Fast Memory Access

AC parameters t_{DIF1} , t_{DIF2} may be used to determine the minimum delays required between \overline{RASIN} , R/\overline{C} , and \overline{CASIN} (see Application Brief 9; "Fastest DRAM Access Mode").

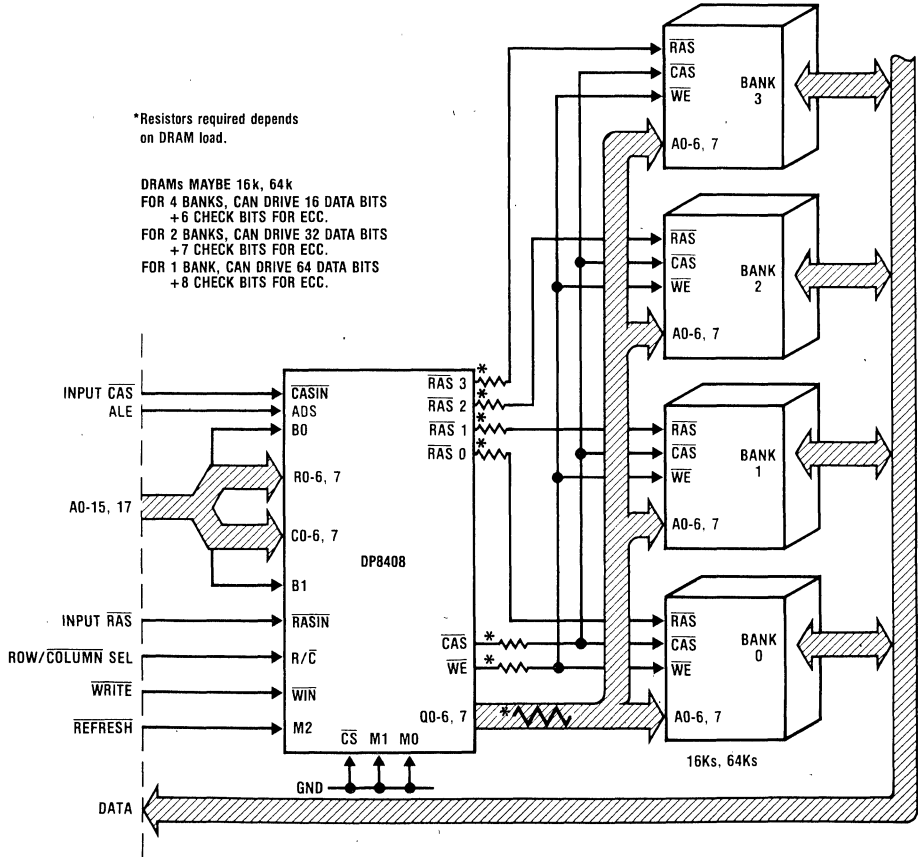


FIGURE 3. Typical Application of DP8408 Using Externally Controlled Access and Refresh in Modes 0 and 4

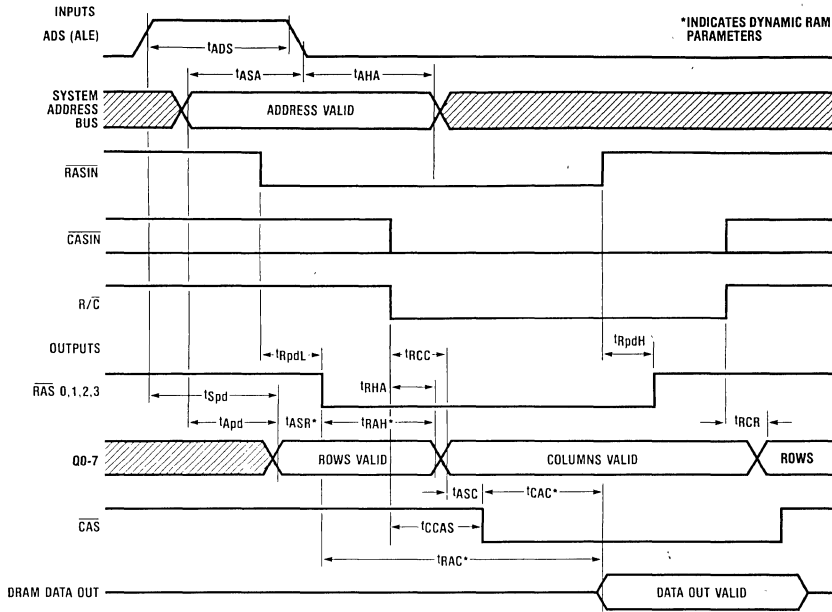


FIGURE 4a. Read Cycle Timing (Mode 4)

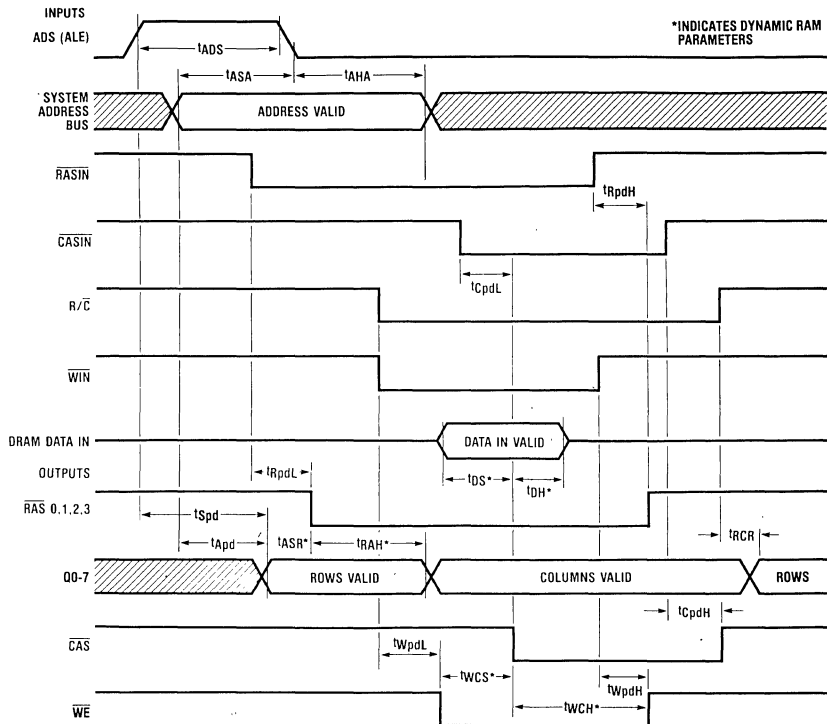


FIGURE 4b. Write Cycle Timing (Mode 4)

Mode 5 — Automatic Access

The Auto Access mode has two advantages over the Externally Controlled Access mode, due to the fact that all outputs except \overline{WE} are initiated from \overline{RASIN} . First, inputs R/C and \overline{CASIN} are unnecessary. Secondly, because the output control signals are derived internally from one input signal (\overline{RASIN}), timing-skew problems are reduced, thereby reducing memory access time substantially or allowing use of slower DRAMs. The automatic access features of Mode 5 (and Mode 6) of the DP8408 make DRAM accessing appear essentially "static".

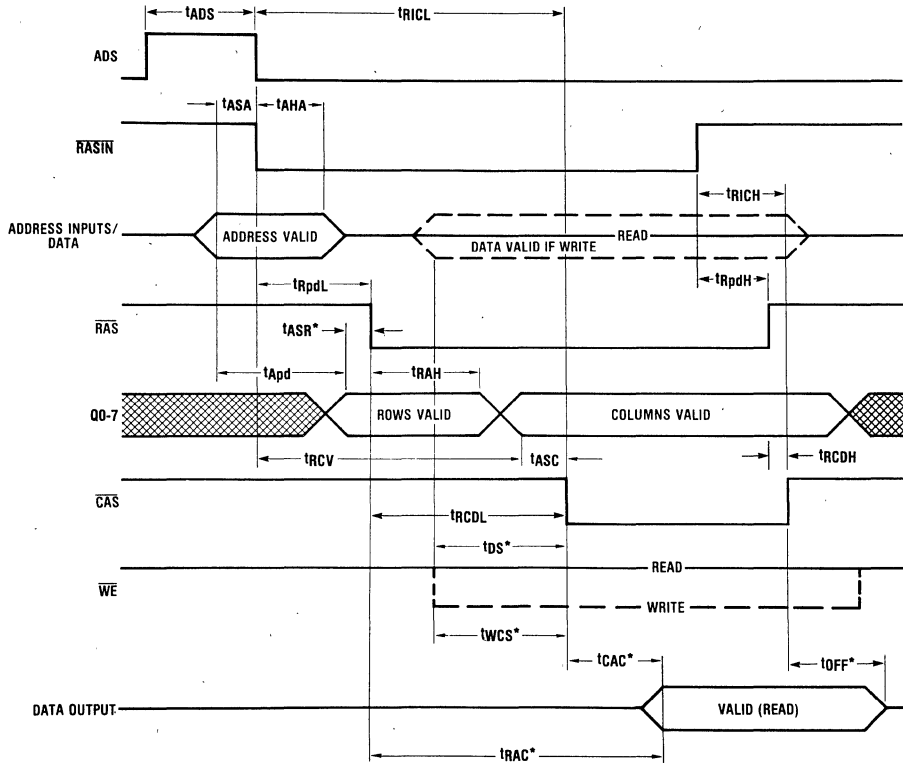
Automatic Access Control

The major disadvantage of DRAMs compared to static RAMs is the complex timing involved. First, a \overline{RAS} must occur with the row address previously set up on the multiplexed address bus. After the row address has been

held for t_{RAH} , (the Row-Address hold-time of the DRAM), the column address is set up and then \overline{CAS} occurs. This is all performed automatically by the DP8408 in this mode.

Provided the input address is valid as ADS goes low, \overline{RASIN} can go low any time after ADS. This is because the selected \overline{RAS} occurs typically 27 ns later, by which time the row address is already valid on the address output of the DP8408. The Address Set-Up time (t_{ASR}), is 0 ns on most DRAMs. The DP8408 in this mode (with ADS and \overline{RASIN} edges simultaneously applied) produces a minimum t_{ASR} of 0 ns. This is true provided the input address was valid t_{ASA} before ADS went low (see Figure 5a).

Next, the row address is disabled after t_{RAH} (30 ns minimum); in most DRAMs, t_{RAH} minimum is less than 30 ns. The column address is then set up and t_{ASC} later, \overline{CAS}



*INDICATES DYNAMIC RAM PARAMETERS

FIGURE 5a. Modes 5, 6 Timing (\overline{CASIN} High in Mode 6)

occurs. The only other control input required is \overline{WIN} . When a write cycle is required, \overline{WIN} must go low at least 30ns before \overline{CAS} is output low.

This gives a total typical delay from: input address valid to \overline{RASIN} (15ns); to \overline{RAS} (27 ns); to rows held (50ns); to columns valid (25ns); to \overline{CAS} (23ns) = 140ns (that is, 125ns from \overline{RASIN}). All of these typical figures are for heavy capacitive loading, of approximately 88 DRAMs. This mode is therefore extremely fast. The external timing is greatly simplified for the memory system designer: the only system signal required is \overline{RASIN} .

Mode 6 — Fast Automatic Access

The Fast Access mode is similar to Mode 5, but has a faster t_{RAH} of 20ns, minimum. It therefore can only be

used with fast 16k or 64k DRAMs (which have a t_{RAH} of 10ns to 15ns) in applications requiring fast access times; \overline{RASIN} to \overline{CAS} is typically 105ns.

In this mode, the R/\overline{C} pin is not used, but \overline{CASIN} is used to allow an extended \overline{CAS} after \overline{RAS} has already terminated. Refer to Figure 5b. This is desirable with fast cycle-times where \overline{RAS} has to be terminated as soon as possible before the next \overline{RAS} begins (to meet the precharge time, or t_{RP} , requirements of the DRAM). \overline{CAS} may then be held low by \overline{CASIN} to extend the data output valid time from the DRAM to allow the system to read the data. \overline{CASIN} subsequently going high ends \overline{CAS} . If this extended \overline{CAS} is not required, \overline{CASIN} should be set high in Mode 6.

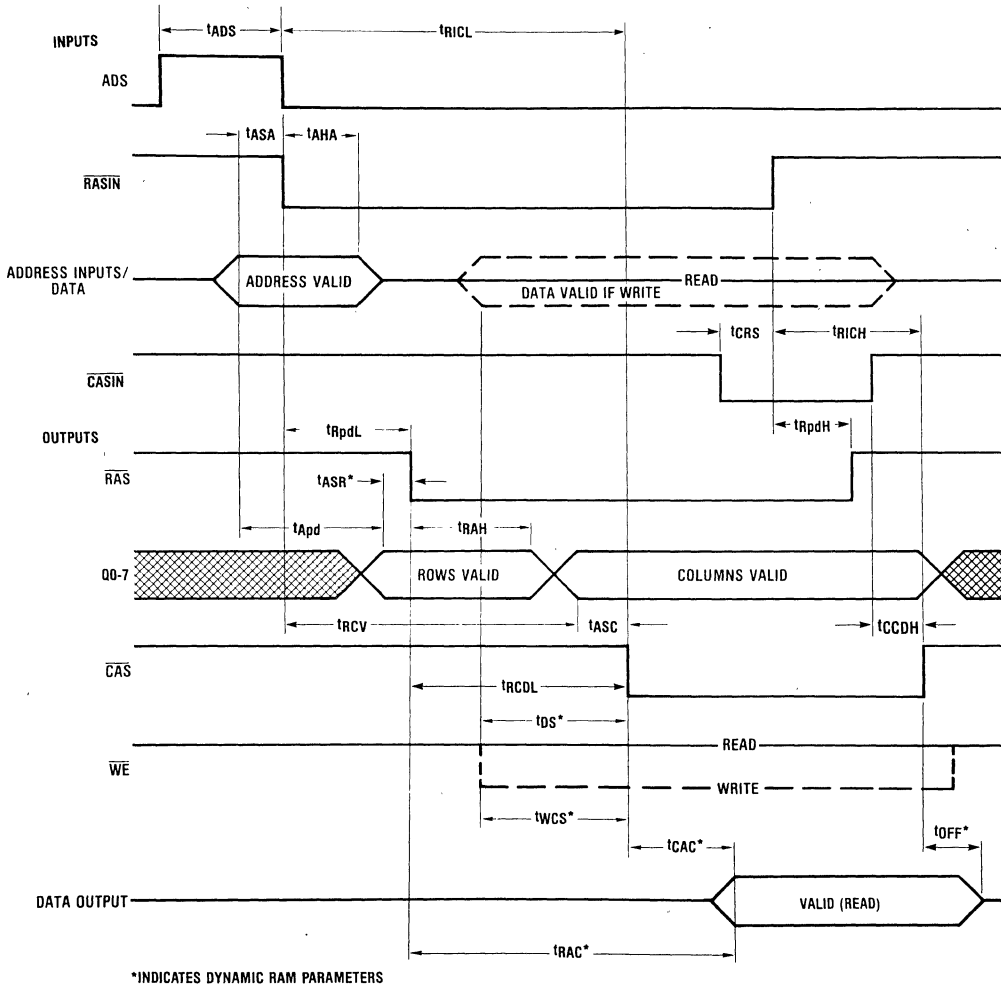


FIGURE 5b. Mode 6 Timing, Extended \overline{CAS}

Mode 7 — Set End-of-Count

The End-of-Count can be externally selected in Mode 7, using ADS to strobe in the respective value of B1 and B0 (see Table 3). With B1 and B0 the same EOC is 127; with B1=0 and B0=1, EOC is 255; and with B1=1 and B0=0, EOC is 127. This selected value of EOC will be used until the next Mode 7 selection. At power-up the EOC is automatically set to 127 (B1 and B0 set to 11).

Table 3. Mode 7

Bank Select (Strobed by ADS)		End of Count Selected
B1	B0	
0	0	127
0	1	255
1	0	127
1	1	127

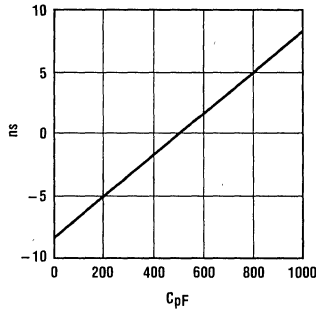


FIGURE 6. Change in Propagation Delay vs. Loading Capacitance Relative to a 500pF Load

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Storage Temperature Range	-65°C to +150°C
Input Voltage	5.5V
Output Current	150 mA
Lead Temperature (Soldering, 10 seconds)	300°C

Maximum Power Dissipation* at 25°C

Cavity Package	3542mW
Molded Package	2833mW

Operating Conditions

V_{CC} Supply Voltage	Min 4.75	Max 5.25	Units V
T_A Ambient Temperature	0	+70	°C

*Derate cavity package 23.6mW/°C above 25°C; derate molded package 22.7mW/°C above 25°C.

Electrical Characteristics $V_{CC} = 5.0V \pm 5\%$, $0^\circ C \leq T_A \leq 70^\circ C$ unless otherwise noted (Notes 2, 6)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_C	Input Clamp Voltage	$V_{CC} = \text{Min.}, I_C = -12 \text{ mA}$		-0.8	-1.2	V
I_{IH1}	Input High Current for ADS, R/\overline{C} only	$V_{IN} = 2.5V$		2.0	100	μA
I_{IH2}	Input High Current for All Other Inputs*	$V_{IN} = 2.5V$		1.0	50	μA
$I_{I \text{ RSI}}$	Output Load Current for RF I/O	$V_{IN} = 0.5V$, Output High		-1.5	-2.5	mA
$I_{I \text{ CTL}}$	Output Load Current for \overline{RAS} , \overline{CAS} , \overline{WE}	$V_{IN} = 0.5V$, Chip Deselect		-1.5	-2.5	mA
I_{IL1}	Input Low Current for ADS, R/\overline{C} only	$V_{IN} = 0.5V$		-0.1	-1.0	mA
I_{IL2}	Input Low Current for All Other Inputs*	$V_{IN} = 0.5V$		-0.05	-0.5	mA
V_{IL}	Input Low Threshold				0.8	V
V_{IH}	Input High Threshold		2.0			V
V_{OL1}	Output Low Voltage*	$I_{OL} = 20 \text{ mA}$		0.3	0.5	V
V_{OL2}	Output Low Voltage for RF I/O	$I_{OL} = 10 \text{ mA}$		0.3	0.5	V
V_{OH1}	Output High Voltage*	$I_{OH} = -1 \text{ mA}$	2.4	3.5		V
V_{OH2}	Output High Voltage for RF I/O	$I_{OH} = -100 \mu A$	2.4	3.5		V
I_{1D}	Output High Drive Current*	$V_{OUT} = 0.8V$ (Note 3)		-200		mA
I_{0D}	Output Low Drive Current*	$V_{OUT} = 2.7V$ (Note 3)		200		mA
I_{OZ}	TRI-STATE Output Current (Address Outputs)	$0.4V \leq V_{OUT} \leq 2.7V$, $\overline{CS} = 2.0V$, Mode 4	-50	1.0	50	μA
I_{CC}	Supply Current	$V_{CC} = \text{Max.}$		210	285	mA

*Except RF I/O Output.

Switching Characteristics: DP8408/DP8408-3 $V_{CC} = 5.0V \pm 5\%$, $0^\circ C \leq T_A \leq 70^\circ C$ unless otherwise noted (Notes 2, 4, 5). The output load capacitance is typical for 4 banks of 22 DRAMs each or 88 DRAMs including trace capacitance. These values are: Q0-Q7, $C_L = 500 \text{ pF}$; RAS0-RAS3, $C_L = 150 \text{ pF}$; \overline{WE} , $C_L = 500 \text{ pF}$; \overline{CAS} , $C_L = 600 \text{ pF}$, unless otherwise noted. See Figure 7 for test load. Switches S1 and S2 are closed unless otherwise noted, and R1 and R2 are 4.7k Ω unless otherwise noted. Maximum propagation delays are specified with all outputs switching.

Symbol	Access Parameter	Conditions	8408			8408 - 3			Units
			Min	Typ	Max	Min	Typ	Max	
t_{R1CL}	\overline{RASIN} to \overline{CAS} Output Delay (Mode 5)	Figure 5a	95	125	160	95	125	185	ns
t_{R1CL}	\overline{RASIN} to \overline{CAS} Output Delay (Mode 6)	Figures 5a, 5b	80	105	140	80	105	160	ns
t_{R1CH}	\overline{RASIN} to \overline{CAS} Output Delay (Mode 5)	Figure 5a	40	48	60	40	48	70	ns
t_{R1CH}	\overline{RASIN} to \overline{CAS} Output Delay (Mode 6)	Figures 5a, 5b	50	63	80	50	63	95	ns
t_{RCDL}	\overline{RAS} to \overline{CAS} Output Delay (Mode 5)	Figure 5a		98	125		98	145	ns
t_{RCDL}	\overline{RAS} to \overline{CAS} Output Delay (Mode 6)	Figures 5a, 5b		78	105		78	120	ns
t_{RCDH}	\overline{RAS} to \overline{CAS} Output Delay (Mode 5)	Figure 5a		27	40		27	40	ns
t_{RCDH}	\overline{RAS} to \overline{CAS} Output Delay (Mode 6)	Figure 5a		40	65		40	65	ns
t_{CCDH}	\overline{CASIN} to \overline{CAS} Output Delay (Mode 6)	Figure 5b	40	54	70	40	54	80	ns
t_{RAH}	Row Address Hold Time (Mode 5)	Figure 5a	30			30			ns
t_{RAH}	Row Address Hold Time (Mode 6)	Figures 5a, 5b	20			20			ns
t_{ASC}	Column Address Setup Time (Mode 5)	Figure 5a	8			8			ns
t_{ASC}	Column Address Setup Time (Mode 6)	Figures 5a, 5b	6			6			ns
t_{RCV}	\overline{RASIN} to Column Address Valid (Mode 5)	Figure 5a		90	120		90	140	ns



Switching Characteristics (Cont'd)

Symbol	Access Parameter	Conditions	8408			8408-3			Units
			Min	Typ	Max	Min	Typ	Max	
t_{RCV}	\overline{RASIN} to Column Address Valid (Mode 6)	Figures 5a, 5b		75	105		75	120	ns
t_{RPDL}	\overline{RASIN} to \overline{RAS} Delay	Figures 4a, 4b, 5a, 5b	20	27	35	20	27	40	ns
t_{RPDH}	\overline{RASIN} to \overline{RAS} Delay	Figures 4a, 4b, 5a, 5b	15	23	32	15	23	37	ns
t_{APDL}	Address Input to Output Low Delay	Figures 4a, 4b, 5a, 5b		25	40		25	46	ns
t_{APDH}	Address Input to Output High Delay	Figures 4a, 4b, 5a, 5b		25	40		25	46	ns
t_{SPDL}	Address Strobe to Address Output Low	Figures 4a, 4b		40	60		40	70	ns
t_{SPDH}	Address Strobe to Address Output High	Figures 4a, 4b		40	60		40	70	ns
t_{ASA}	Address Setup Time to ADS	Figures 4a, 4b, 5a, 5b	15			15			ns
t_{AHA}	Address Hold Time from ADS	Figures 4a, 4b, 5a, 5b	15			15			ns
t_{ADS}	Address Strobe Pulse Width	Figures 4a, 4b, 5a, 5b	30			30			ns
t_{WPDL}	\overline{WIN} to \overline{WE} Output Delay	Figure 4b	15	25	30	15	25	35	ns
t_{WPDH}	\overline{WIN} to \overline{WE} Output Delay	Figure 4b	15	30	60	15	30	70	ns
t_{CRS}	\overline{CASIN} Setup Time to \overline{RASIN} High (Mode 6)	Figure 5b	35			35			ns
t_{CPDL}	\overline{CASIN} to \overline{CAS} Delay (R/\overline{C} low in Mode 4)	Figure 4b	32	41	68	32	41	77	ns
t_{CPDH}	\overline{CASIN} to \overline{CAS} Delay	Figure 4b	25	39	50	25	39	60	ns
t_{RCC}	Column Select to Column Address Valid	Figure 4a		40	58		40	67	ns
t_{RCR}	Row Select to Row Address Valid	Figures 4a, 4b		40	58		40	67	ns
t_{RHA}	Row Address Held from Column Select	Figure 4a	10			10			ns
t_{CCAS}	R/\overline{C} Low to \overline{CAS} Low (Mode 4 Auto \overline{CAS})	Figure 7a		65	90				ns
t_{DIF1}	Maximum ($t_{RPDL} - t_{RHA}$)	See Mode 4 description				13		18	ns
t_{DIF2}	Maximum ($t_{RCC} - t_{CPDL}$)	See Mode 4 description				13		18	ns
Refresh Parameter									
t_{RC}	Refresh Cycle Period	Figure 2	100			100			ns
$t_{RASINLH}$	Pulse Width of \overline{RASIN} during Refresh	Figure 2	50			50			ns
t_{RFPDL}	\overline{RASIN} to \overline{RAS} Delay during Refresh	Figure 2	35	50	70	35	50	80	ns
t_{RFPDH}	\overline{RASIN} to \overline{RAS} Delay during Refresh	Figure 2	30	40	55	30	40	65	ns
t_{RFLCT}	\overline{RFSH} Low to Counter Address Valid	$\overline{CS} = X$, Figure 2		47	60		47	70	ns
t_{RFHRV}	\overline{RFSH} High to Row Address Valid	Figure 2		45	60		45	70	ns
t_{ROHNC}	\overline{RAS} High to New Count Valid	Figure 2		30	55		30	55	ns
t_{RLEOC}	\overline{RASIN} Low to End-of-Count Low	$C_L = 50pF$, Figure 2			80			80	ns
t_{RHEOC}	\overline{RASIN} High to End-of-Count High	$C_L = 50pF$, Figure 2			80			80	ns
t_{RST}	Counter Reset Pulse Width	Figure 2	70			70			ns
t_{CTL}	RF I/O Low to Counter Outputs All Low	Figure 2			100			100	ns
TRI-STATE Parameter									
t_{ZH}	\overline{CS} Low to Address Output High from Hi-Z	Figure 8 $R1 = 3.5k, R2 = 1.5k$		35	60		35	60	ns
t_{HZ}	\overline{CS} High to Address Output Hi-Z from High	$C_L = 15pF$, Figure 8 $R2 = 1k, S1$ open		20	40		20	40	ns
t_{ZL}	\overline{CS} Low to Address Output Low from Hi-Z	Figure 8 $R1 = 3.5k, R2 = 1.5k$		35	60		35	60	ns
t_{LZ}	\overline{CS} High to Address Output Hi-Z from Low	$C_L = 15pF$, Figure 8, $R1 = 1k, S2$ open		25	50		25	50	ns

Switching Characteristics (Cont'd)

Symbol	TRI-STATE Parameter	Conditions	8408			8408 - 3			Units
			Min	Typ	Max	Min	Typ	Max	
t_{HZH}	\overline{CS} Low to Control Output High from Hi-Z High	Figure 8 $R_2 = 750\Omega$, S1 open		50	80		50	80	ns
t_{HHZ}	\overline{CS} High to Control Output Hi-Z High from High	$C_L = 15\text{pF}$, Figure 8 $R_2 = 750\Omega$, S1 open		40	75		40	75	ns
t_{HZL}	\overline{CS} Low to Control Output Low from Hi-Z High	Figure 8 S1, S2 open		45	75		45	75	ns
t_{LHZ}	\overline{CS} High to Control Output Hi-Z High from Low	$C_L = 15\text{pF}$, Figure 8, $R_2 = 750\Omega$, S1 open		50	80		50	80	ns

Switching Characteristics: DP8408-2 $V_{CC} = 5.0V \pm 5\%$, $0^\circ\text{C} \leq T_A \leq 70^\circ\text{C}$ unless otherwise noted (Notes 2, 4, 5, 7). The output load capacitance is typical for 4 banks of 22 DRAMs each or 88 DRAMs including trace capacitance. These values are: Q0-Q7, $C_L = 500\text{pF}$; RAS0-RAS3, $C_L = 150\text{pF}$; WE, $C_L = 500\text{pF}$; CAS, $C_L = 600\text{pF}$, unless otherwise noted. See Figure 7 for test load. Switches S1 and S2 are closed unless otherwise noted, and R1 and R2 are $4.7k\Omega$ unless otherwise noted. Maximum propagation delays are specified with all outputs switching.

Symbol	Access Parameter	Conditions	8408 - 2			8408 - 3			Units
			Min	Typ	Max	Min	Typ	Max	
t_{RICL}	\overline{RAS} to \overline{CAS} Output Delay (Mode 5)	Figure 5a	75	100	130				ns
t_{RICL}	\overline{RAS} to \overline{CAS} Output Delay (Mode 6)	Figures 5a, 5b	65	90	115				ns
t_{RICH}	\overline{RAS} to \overline{CAS} Output Delay (Mode 5)	Figure 5a	40	48	60				ns
t_{RICH}	\overline{RAS} to \overline{CAS} Output Delay (Mode 6)	Figures 5a, 8b	50	63	80				ns
t_{RCDL}	\overline{RAS} to \overline{CAS} Output Delay (Mode 5)	Figure 5a		75	100				ns
t_{RCDL}	\overline{RAS} to \overline{CAS} Output Delay (Mode 6)	Figures 5a, 5b		65	85				ns
t_{RCDH}	\overline{RAS} to \overline{CAS} Output Delay (Mode 5)	Figure 5a		27	40				ns
t_{RCDH}	\overline{RAS} to \overline{CAS} Output Delay (Mode 6)	Figure 5a		40	65				ns
t_{CCDH}	\overline{CAS} to \overline{CAS} Output Delay (Mode 6)	Figure 5b	40	54	70				ns
t_{RAH}	Row Address Hold Time (Mode 5) (Note 7)	Figure 5a	20						ns
t_{RAH}	Row Address Hold Time (Mode 6) (Note 7)	Figures 5a, 5b	12						ns
t_{ASC}	Column Address Setup Time (Mode 5)	Figure 5a	3						ns
t_{ASC}	Column Address Setup Time (Mode 6)	Figures 5a, 8b	3						ns
t_{RCV}	\overline{RAS} to Column Address Valid (Mode 5)	Figure 5a		80	105				ns
t_{RCV}	\overline{RAS} to Column Address Valid (Mode 6)	Figures 5a, 5b		70	90				ns
t_{RPDL}	\overline{RAS} to \overline{RAS} Delay	Figures 4a, 4b, 5a, 5b	20	27	35				ns
t_{RPDH}	\overline{RAS} to \overline{RAS} Delay	Figures 4a, 4b, 5a, 5b	15	23	32				ns
t_{APDL}	Address Input to Output Low Delay	Figures 4a, 4b, 5a, 5b		25	40				ns
t_{APDH}	Address Input to Output High Delay	Figures 4a, 4b, 5a, 5b		25	40				ns
t_{SPDL}	Address Strobe to Address Output Low	Figures 4a, 4b		40	60				ns
t_{SPDH}	Address Strobe to Address Output High	Figures 4a, 4b		40	60				ns
t_{ASA}	Address Set-up Time to ADS	Figures 4a, 4b, 5a, 5b	15						ns
t_{AHA}	Address Hold Time from ADS	Figures 4a, 4b, 5a, 5b	15						ns
t_{ADS}	Address Strobe Pulse Width	Figures 4a, 4b, 5a, 5b	30						ns
t_{WPDL}	\overline{WIN} to \overline{WE} Output Delay	Figure 4b	15	25	30				ns
t_{WPDH}	\overline{WIN} to \overline{WE} Output Delay	Figure 4b	15	30	60				ns
t_{CRS}	\overline{CAS} Set-up Time to \overline{RAS} High (Mode 6)	Figure 5b	35						ns
t_{CPDL}	\overline{CAS} to \overline{CAS} Delay (Ri/ \overline{C} low in Mode 4)	Figure 4b	32	41	58				ns

Switching Characteristics (Cont'd)

Symbol	Access Parameter	Conditions	8408 - 2						Units
			Min	Typ	Max	Min	Typ	Max	
t_{CPDL}	\overline{CAS} IN to \overline{CAS} Delay (R/C low in Mode 4)	Figure 4b	25	39	50				ns
t_{RCC}	Column Select to Column Address Valid	Figure 4a		40	58				ns
t_{RCR}	Row Select to Row Address Valid	Figures 4a, 4b		40	58				ns
t_{RHA}	Row Address Held from Column Select	Figure 4a	10						ns
t_{CCAS}	R/C Low to \overline{CAS} Low (Mode 4 Auto \overline{CAS})	Figure 7a		55	75				ns
t_{DIF1}	Maximum ($t_{RPDL} - t_{RHA}$)	See Mode 4 description			13				ns
t_{DIF2}	Maximum ($t_{RCC} - t_{CPDL}$)	See Mode 4 description			13				ns
Refresh Parameter									
t_{RC}	Refresh Cycle Period	Figure 2	100						ns
$t_{RASINLH}$	Pulse Width of \overline{RAS} IN during Refresh	Figure 2	50						ns
t_{RFPDL}	\overline{RAS} IN to \overline{RAS} Delay during Refresh	Figure 2	35	50	70				ns
t_{RFPDH}	\overline{RAS} IN to \overline{RAS} Delay during Refresh	Figure 2	30	40	55				ns
t_{RFLCT}	\overline{RFSH} Low to Counter Address Valid	$\overline{CS} = X$, Figure 2		47	60				ns
t_{RFHRV}	\overline{RFSH} High to Row Address Valid	Figure 2		45	60				ns
t_{ROHNC}	\overline{RAS} High to New Count Valid	Figure 2		30	55				ns
t_{RLEOC}	\overline{RAS} IN Low to End-of-Count Low	$C_L = 50\text{pF}$, Figure 2			80				ns
t_{RHEOC}	\overline{RAS} IN High to End-of-Count High	$C_L = 50\text{pF}$, Figure 2			80				ns
t_{RST}	Counter Reset Pulse Width	Figure 2	70						ns
t_{CTL}	RF I/O Low to Counter Outputs All Low	Figure 2			100				ns
TRI-STATE Parameter									
t_{ZH}	\overline{CS} Low to Address Output High from Hi-Z	Figures 9, 12 $R_1 = 3.5\text{k}$, $R_2 = 1.5\text{k}$		35	60				ns
t_{HZ}	\overline{CS} High to Address Output Hi-Z from High	$C_L = 15\text{pF}$, Figures 9, 12 $R_2 = 1\text{k}$, S_1 open		20	40				ns
t_{ZL}	\overline{CS} Low to Address Output Low from Hi-Z	Figures 9, 12 $R_1 = 3.5\text{k}$, $R_2 = 1.5\text{k}$		35	60				ns
t_{LZ}	\overline{CS} High to Address Output Hi-Z from Low	$C_L = 15\text{pF}$, Figures 9, 12 $R_1 = 1\text{k}$, S_2 open		25	50				ns
t_{HZH}	\overline{CS} Low to Control Output High from Hi-Z High	Figures 9, 12 $R_2 = 750\Omega$, S_1 open		50	80				ns
t_{HHZ}	\overline{CS} High to Control Output Hi-Z High from High	$C_L = 15\text{pF}$, Figures 9, 12 $R_2 = 750\Omega$, S_1 open		40	75				ns
t_{HZL}	\overline{CS} Low to Control Output Low from Hi-Z High	Figure 12, S_1 , S_2 open		45	75				ns
t_{LHZ}	\overline{CS} High to Control Output Hi-Z High from Low	$C_L = 15\text{pF}$, Figure 12, $R_2 = 750\Omega$, S_1 open		50	80				ns

Input Capacitance $T_A = 25^\circ\text{C}$ (Notes 2, 6)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C_{IN}	Input Capacitance ADS, R/\bar{C}			8		μF
C_{IN}	Input Capacitance All Other Inputs			5		μF

Note 1: "Absolute Maximum Ratings" are the values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0\text{V}$.

Note 3: This test is provided as a monitor of Driver output source and sink current capability. Caution should be exercised in testing this parameter. In testing these parameters, a 15Ω resistor should be placed in series with each output under test. One output should be tested at a time and test time should not exceed 1 second.

Note 4: Input pulse 0V to 3.0V , $t_R = t_F = 2.5\text{ns}$, $f = 2.5\text{MHz}$, $t_{PW} = 200\text{ns}$. Input reference point on AC measurements is 1.5V . Output reference points are 2.7V for High and 0.8V for Low.

Note 5: The load capacitance on RF I/O should not exceed 50pF .

Note 6: Applies to all DP8408 versions unless otherwise specified.

Note 7: The DP8408-2 device can only be used with memory devices that meet the t_{RAH} specification indicated.

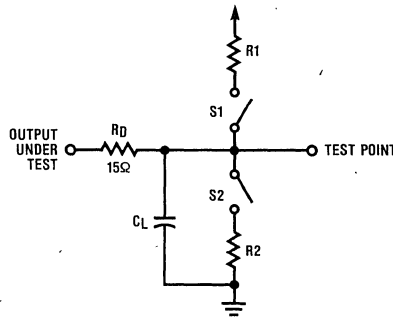


FIGURE 7. Output Load Circuit

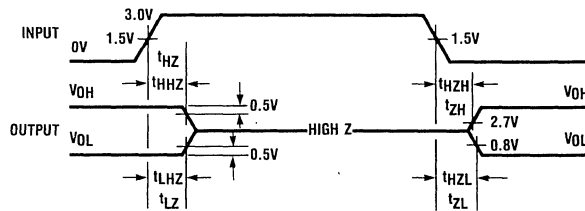


FIGURE 8. Waveform

Applications

If external control is preferred, the DP8408 may be used in Modes 0 or 4, as in Figure 3.

If basic auto access and refresh are required, then in cases where the user requires the minimum of external complexity, Modes 0 and 5 are ideal, as shown in Figure 9a. The DP843X2 is used to provide proper arbitration between memory access and refresh. This chip supplies all the necessary control signals to the processor as well as

the DP8408. Furthermore, two separate $\overline{\text{CAS}}$ outputs are also included for systems using byte-writing. The refresh clock RFCK may be divided down from either RGCK using an IC counter such as the DM74LS393 or better still, the DP84300 Programmable Refresh Timer. The DP84300 can provide RFCK periods ranging from 15.4 μs to 15.6 μs based on the input clock of 2 to 10 MHz. Figure 9b shows the general timing diagram for interfacing the DP8408 to different microprocessors using the interface controller DP843X2.

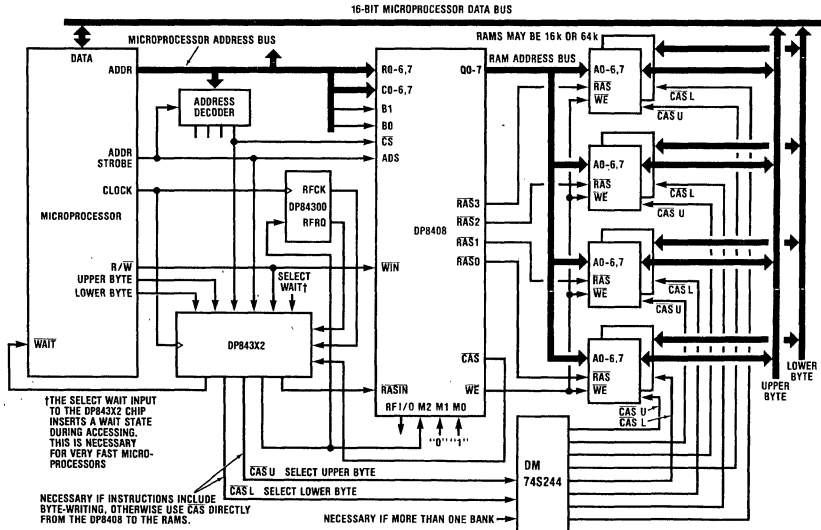


FIGURE 9a. Connecting the DP8408 Between the 16-Bit Microprocessor and Memory

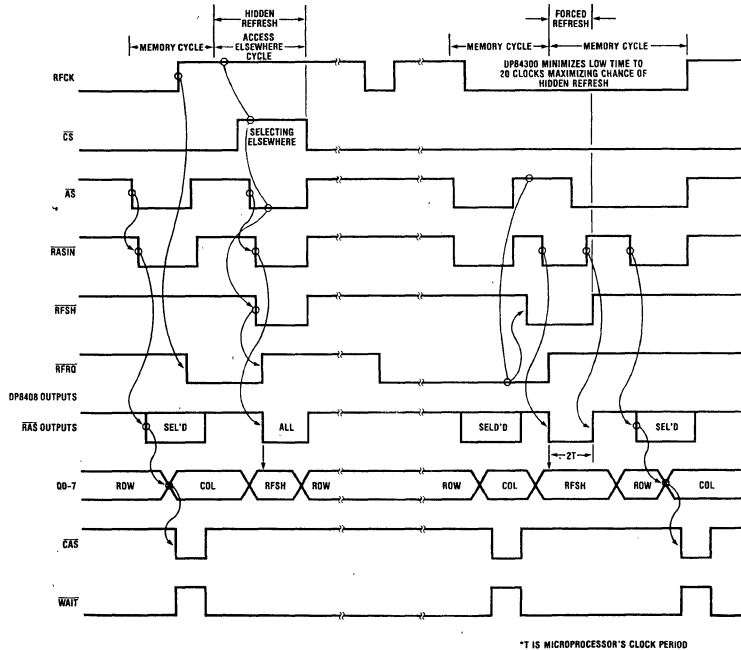


FIGURE 9b. DP8408 Auto Refresh

DP8409 Multi-Mode Dynamic RAM Controller/Driver

General Description

Dynamic memory system designs, which formerly required several support chips to drive the memory array, can now be implemented with a single IC... the DP8409 Multi-Mode Dynamic RAM Controller/Driver. The DP8409 is capable of driving all 16k and 64k Dynamic RAMs (DRAMs) as well as 256k DRAMs. Since the DP8409 is a one-chip solution (including capacitive-load drivers), it minimizes propagation delay skews, the major performance disadvantage of multiple-chip memory drive and control.

The DP8409's 8 modes of operation offer a wide selection of DRAM control capabilities. Memory access may be controlled externally or on-chip automatically; an on-chip refresh counter makes refreshing (either externally or automatically controlled) less complicated; and automatic memory initialization is both simple and fast.

The DP8409 is a 48-pin DRAM Controller/Driver with 9 multiplexed address outputs and 6 control signals. It consists of two 9-bit address latches, a 9-bit refresh counter, and control logic. All output drivers are capable of driving 500pF loads with propagation delays of 25ns. The DP8409 timing parameters are specified driving the typical load capacitance of 88 DRAMs, including trace capacitance.

The DP8409 has 3 mode-control pins: M2, M1, and M0, where M2 is in general $\overline{\text{REFRESH}}$. These 3 pins select 8 modes of operation. Inputs B1 and B0 in the memory access modes (M2 = 1), are select inputs which select one of four $\overline{\text{RAS}}$ outputs. During normal access, the 9 address outputs can be selected from the Row Address Latch or the Column Address Latch. During refresh, the 9-bit on-chip refresh counter is enabled onto the address bus and in this mode all $\overline{\text{RAS}}$ outputs are selected, while $\overline{\text{CAS}}$ is inhibited.

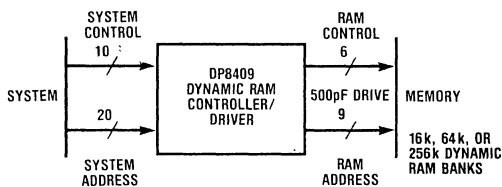
The DP8409 can drive up to 4 banks of DRAMs, with each bank comprised of 16k's, 64k's, or 256k's. Control signal outputs $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, and $\overline{\text{WE}}$ are provided with the same drive capability. Each $\overline{\text{RAS}}$ output drives one bank of DRAMs so that the four $\overline{\text{RAS}}$ outputs are used to select the banks, while $\overline{\text{CAS}}$, $\overline{\text{WE}}$, and the multiplexed addresses can be connected to all of the banks of DRAMs. This leaves the non-selected banks in the standby mode (less than one tenth of the operating power) with the data outputs in TRI-STATE[®]. Only the bank with its associated $\overline{\text{RAS}}$ low will be written to or read from.

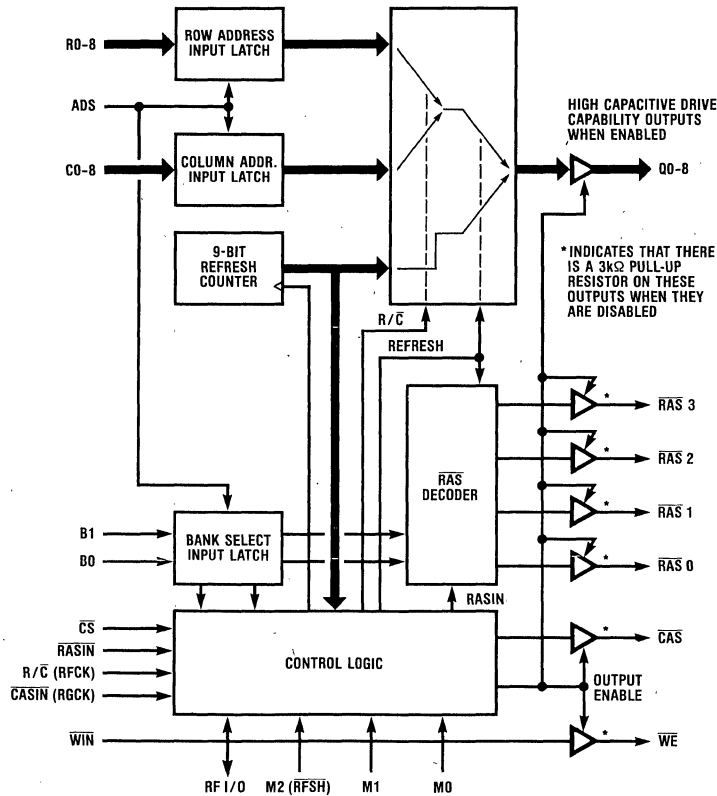
Operational Features

- All DRAM drive functions on one chip — minimizes skew on outputs, maximizes AC performance
- On-chip capacitive-load drives (specified to drive up to 88 DRAMs)
- Drives directly all 16k, 64k, and 256k DRAMs
- Capable of addressing 64k, 256k, or 1M words
- Propagation delays of 25 ns typical at 500pF load
- $\overline{\text{CAS}}$ goes low automatically after column addresses are valid if desired
- Auto Access mode provides $\overline{\text{RAS}}$, row to column select, then $\overline{\text{CAS}}$ automatically and fast
- $\overline{\text{WE}}$ follows $\overline{\text{WIN}}$ unconditionally—offering READ, WRITE or READ-MODIFY-WRITE cycles
- On-chip 9-bit refresh counter with selectable End-of-Count (127, 255, or 511)
- End-of-Count indicated by RF I/O pin going low at 127, 255, or 511
- Low input on RF I/O resets 9-bit refresh counter
- $\overline{\text{CAS}}$ inhibited during refresh cycle
- Fall-through latches on address inputs controlled by ADS
- TRI-STATE outputs allow multi-controller addressing of memory
- Control output signals go high-impedance logic "1" when disabled for memory sharing
- Power-up: counter reset, control signals high, address outputs TRI-STATE, and End-of-Count set to 127

Mode Features

- 8 modes of operation: 3 access, 3 refresh, and 2 set-up
- 2 externally controlled modes: 1 access and 1 refresh (Modes 0, 4)
- 2 auto-access modes $\overline{\text{RAS}} \rightarrow \overline{\text{R/C}} \rightarrow \overline{\text{CAS}}$ automatic, with $t_{\text{RAH}} = 20$ or 30ns minimum (Modes 5, 6)
- Auto-access mode allows Hidden Refreshing (Mode 5)
- Forced Refresh requested on RF I/O if no Hidden Refresh (Mode 5)
- Forced Refresh performed after system acknowledge of request (Mode 1)
- Automatic Burst Refresh mode stops at End-of-Count of 127, 255, or 511 (Mode 2)
- 2 All- $\overline{\text{RAS}}$ Access modes externally or automatically controlled for memory initialization (Modes 3a, 3b)
- Automatic All- $\overline{\text{RAS}}$ mode with external 8-bit counter frees system for other set-up routines (Mode 3a)
- End-of-Count value of Refresh Counter set by B1 and B0 (Mode 7)





DP8409 Functional Block Diagram

Pin Definitions

V_{CC}, GND, GND — V_{CC} = 5V ± 5%. The three supply pins have been assigned to the center of the package to reduce voltage drops, both DC and AC. There are also two ground pins to reduce the low level noise. The second ground pin is located two pins from V_{CC}, so that decoupling capacitors can be inserted directly next to these pins. It is important to adequately decouple this device, due to the high switching currents that will occur when all 9 address bits change in the same direction simultaneously. A recommended solution would be a 1μF multilayer ceramic capacitor in parallel with a low-voltage tantalum capacitor, both connected as close as possible to pins 36 and 38 to reduce lead inductance. See Figure below.



*Capacitor values should be chosen depending on the particular application.

R0-R8: Row Address Inputs.

C0-C8: Column Address Inputs.

Q0-Q8: Multiplexed Address Outputs — Selected from the Row Address Input Latch, the Column Address Input Latch, or the Refresh Counter.*

RASIN: Row Address Strobe Input — Enables selected RAS_n output when M2 (RFSH) is high, or all RAS_n outputs when RFSH is low.

R/C (RFCK) — In Auto-Refresh Mode this pin is the external Refresh Clock Input: one refresh cycle has to be performed each clock period. In all other modes it is Row/Column Select Input: selects either the row or column address input latch onto the output bus.

CASIN (RGCK) — In Auto-Refresh Mode, Auto Burst Mode, and All-RAS Auto-Write Mode, this pin is the RAS Generator Clock input. In all other modes it is CASIN (Column Address Strobe Input), which inhibits CAS output when high in Modes 4 and 3b. In Mode 6 it can be used to prolong CAS output.

ADS: Address (Latch) Strobe Input — Row Address, Column Address, and Bank Select Latches are fall-through with ADS high; Latches on high-to-low transition.

CS: Chip Select Input — TRI-STATE's the Address Outputs and puts the control signal into a high-impedance logic "1" state when high (unless refreshing in one of the Refresh Modes). Enables all outputs when low.

M0, M1, M2: Mode Control Inputs — These 3 control pins determine the 8 major modes of operation of the DP8409 as depicted in Table 1.

Table 1. DP8409 Mode Select Options

Mode	(RFSH) M2	M1	M0	Mode of Operation	Conditions
0	0	0	0	Externally Controlled Refresh	RF I/O = $\overline{E\overline{O}C}$
1	0	0	1	Auto Refresh — forced	RF I/O = Refresh Request (\overline{RFRQ})
2	0	1	0	Internal Auto Burst Refresh	RF I/O = $\overline{E\overline{O}C}$
3a	0	1	1	All \overline{RAS} Auto Write	RF I/O = $\overline{E\overline{O}C}$; All \overline{RAS} Active
3b	0	1	1	Externally Controlled All \overline{RAS} Access	All \overline{RAS} Active
4	1	0	0	Externally Controlled Access	Active \overline{RAS} defined by Table 2
5	1	0	1	Auto Access, Slow t_{RAH} , Hidden Refresh	Active \overline{RAS} defined by Table 2
6	1	1	0	Auto Access, Fast t_{RAH}	Active \overline{RAS} defined by Table 2
7	1	1	1	Set End of Count	See Table 3 for Mode 7

RF I/O — The I/O pin functions as a Reset Counter Input when set low from an external open-collector gate, or as a flag output. The flag goes active-low in Modes 0 and 2 when the End-of-Count output is at 127, 255, or 511 (see Table 3), in Auto-Refresh Mode it is the Refresh Request output.

\overline{WIN} : Write Enable Input.

\overline{WE} : Write Enable Output — Buffered output from \overline{WIN} .*

\overline{CAS} : Column Address Strobe Output — In Modes 3a, 5, and 6, \overline{CAS} transitions low following valid column address. In Modes 3b and 4, it goes low after R/\overline{C} goes low, or follows \overline{CASIN} going low if R/\overline{C} is already low. \overline{CAS} is high during refresh.*

\overline{RAS} 0-3: Row Address Strobe Outputs — Selects a memory bank decoded from B1 and B0 (see Table 2), if RFSH is high. If RFSH is low, all banks are selected.*

B0, B1: Bank Select Inputs — Strobed by ADS. Decoded to enable one of the RAS outputs when \overline{RASIN} goes low. Also used to define End-of-Count in Mode 7 (Table 3).

Conditions for all Modes

Input Addressing

The address block consists of a row-address latch, a column-address latch, and a resettable refresh counter. The address latches are fall-through when ADS is high and latch when ADS goes low. If the address bus contains valid addresses until after the valid address time, ADS can be permanently high. Otherwise ADS must go low while the addresses are still valid.

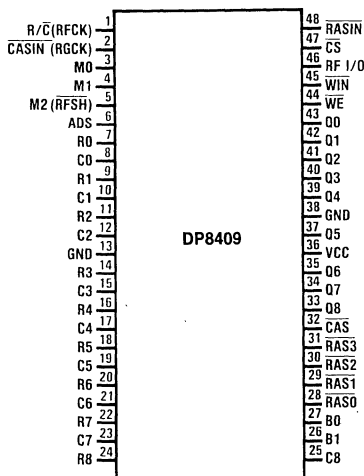
In normal memory access operation, \overline{RASIN} and R/\overline{C} are initially high. When the address inputs are enabled into the address latches, the row addresses appear on the Q outputs. The address strobe also inputs the bank-select address, (B0 and B1). If \overline{CS} is low, all outputs are enabled. When \overline{CS} is transitioned high, the address outputs go TRI-STATE and the control outputs first go high through a low impedance, and then are held by an on-chip high impedance. This allows output paralleling with other DP8409s for multi-addressing. All outputs go active about 50ns after the chip is selected again. If \overline{CS} is high, and a refresh cycle begins, all the outputs become active until the end of the refresh cycle.

Drive Capability

The DP8409 has timing parameters that are specified with up to 600pF loads. In a typical memory system this is equivalent to about 88, 5V-only DRAMs, with trace lengths kept to a minimum. Therefore, the chip can drive four banks each of 16 or 22 bits, or two banks of 32 or 39 bits, or one bank of 64 or 72 bits.

Less loading will slightly reduce the timing parameters, and more loading will increase the timing parameters, according to the graph of Figure 10. The AC performance parameters are specified with the typical load capacitance of 88 DRAMs. This graph can be used to extrapolate the variations expected with other loading.

Because of distributed trace capacitance and inductance and DRAM input capacitance, current spikes can be created, causing overshoots and undershoots at the DRAM inputs that can change the contents of the DRAMs or even destroy them. To remove these spikes, a damping resistor (low inductance, carbon) can be inserted between the DP8409 driver outputs and the DRAMs, as close as possible to the DP8409. The values



Order Number DP8409N, DP8409N-2, DP8409N-3,
 DP8409D, DP8409D-2, DP8409D-3
 See NS package N48A or D48A

Pin Configuration

of the damping resistors may differ between the different control outputs; RAS's, CAS, Q's, and WE. The damping resistors should be determined by the first prototypes (not wire-wrapped due to the larger distributed capacitance and inductance). The best values for the damping resistors are the critical values giving a critically damped transition on the control outputs. Typical values for the damping resistors will be between 15Ω and 100Ω, the lower the loading the higher the value. (For more information, see AN-305 "Precautions to Take When Driving Memories.")

DP8409 Driving any 16k or 64k DRAMs

The DP8409 can drive any 16k or 64k DRAMs. All 16k DRAMs are basically the same configuration, including the newer 5V-only version. Hence, in most applications, different manufacturers' DRAMs are interchangeable

(for the same supply-rail chips), and the DP8409 can drive all 16k DRAMs (see Figure 1a).

There are three basic configurations for the 5V-only 64k DRAMs: a 128-row by 512-column array with an on-RAM refresh counter, a 128-row by 512-column array with no on-RAM refresh counter, and a 256-row by 256-column array with no on-RAM refresh counter. The DP8409 can drive all three configurations, and at the same time allows them all to be interchangeable (as shown in Figures 1b and 1c), providing maximum flexibility in the choice of DRAMs. Since the 9-bit on-chip refresh counter can be used as a 7-bit refresh counter for the 128-row configuration, or as an 8-bit refresh counter for the 256-row configuration, the on-RAM refresh counter (if present) is never used. As long as 128 rows are refreshed every 2ms (i.e. 256 rows in 4ms) all DRAM types are correctly refreshed.

DP8409 Interface Between System & DRAM Banks

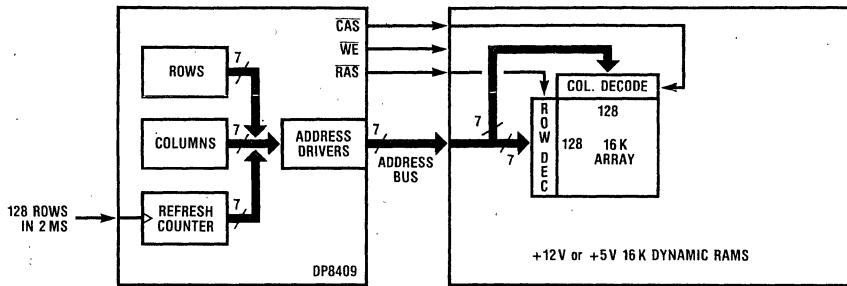


FIGURE 1a. DP8409 with any 16k DRAMs

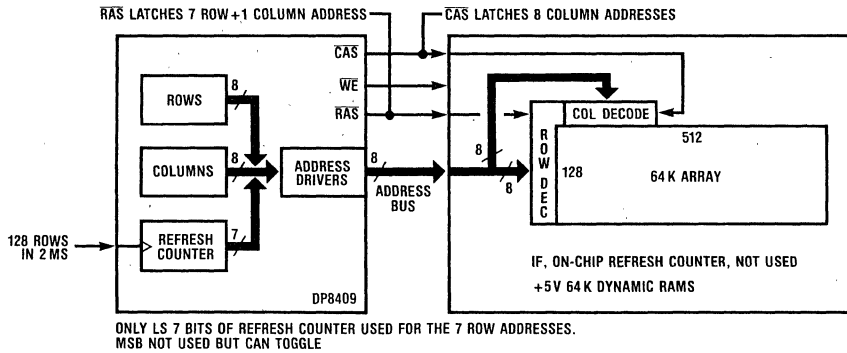


FIGURE 1b. DP8409 with 128 Row x 512 Column 64k DRAM

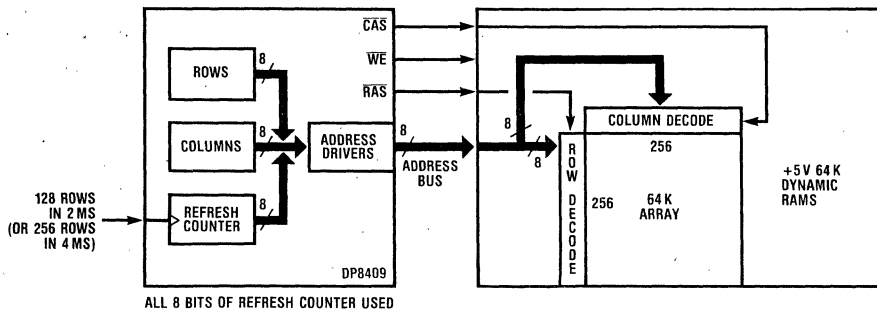


FIGURE 1c. DP8409 with 256 x 256 Column 64k DRAM

When the DP8409 is in a refresh mode, the RF I/O pin indicates that the on-chip refresh counter has reached its end-of-count. This end-of-count is selectable as 127, 255 or 512 to accommodate 16k, 64k, or 256k DRAMs. Although the end-of-count may be chosen to be any of these, the counter always counts to 511 before rolling over to zero.

Read, Write, and Read-Modify-Write Cycles

The output signal, \overline{WE} , determines what type of memory access cycle the memory will perform. If \overline{WE} is kept high while \overline{CAS} goes low, a read cycle occurs. If \overline{WE} goes low before \overline{CAS} goes low, a write cycle occurs and data at DI (DRAM input data) is written into the DRAM as \overline{CAS} goes low. If \overline{WE} goes low later than t_{CWD} after \overline{CAS} goes low, first a read occurs and DO (DRAM output data) becomes valid; then data DI is written into the same address in the DRAM when \overline{WE} goes low. In this read-modify-write case, DI and DO cannot be linked together. The type of cycle is therefore controlled by \overline{WE} , which follows WIN.

Power-Up Initialize

When V_{CC} is first applied to the DP8409, an initialize pulse clears the refresh counter, the internal control flip-flops, and sets the End-of-Count of the refresh counter to 127 (which may be changed via Mode 7). As V_{CC} increases to about 2.3 volts, it holds the output control signals at a level of one Schottky diode-drop below V_{CC} , and the output address to TRI-STATE. As V_{CC} increases above 2.3 volts, control of these outputs is granted to the system.

DP8409 Functional Mode Descriptions

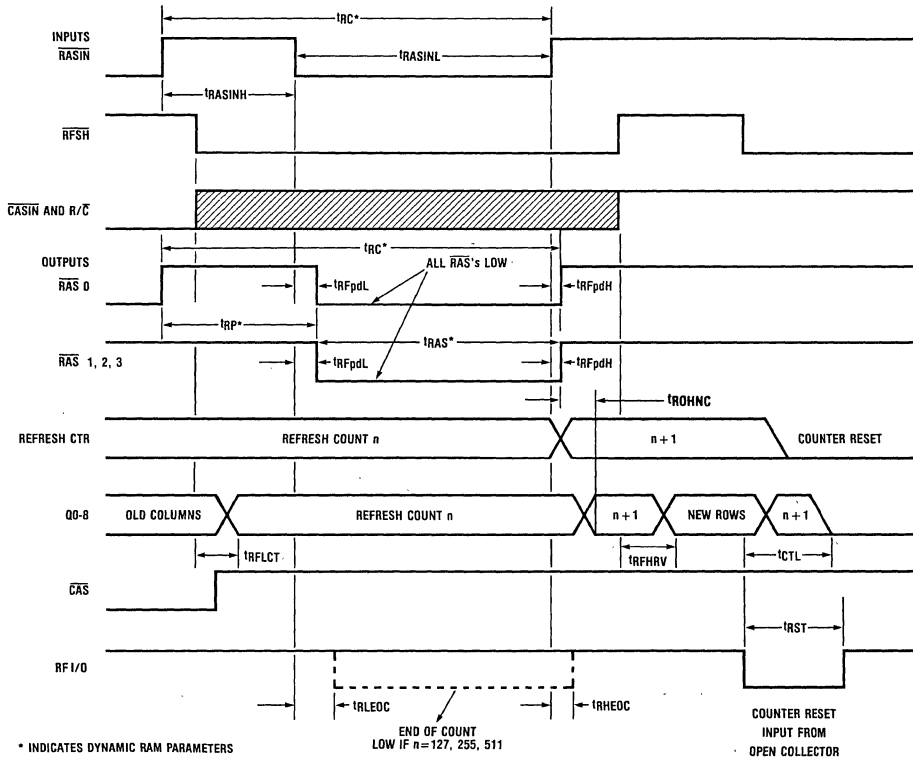
Note: All delay parameters stated in text refer to the DP8409. Substitute the respective delay numbers for the DP8409-2 or DP8409-3 when using these devices.

Mode 0 — Externally Controlled Refresh

Figure 2 is the Externally Controlled Refresh Timing. In this mode, the input address latches are disabled from the address outputs and the refresh counter is enabled. When \overline{RAS} occurs, the enabled row in the DRAM is refreshed. In the Externally Controlled Refresh mode, all \overline{RAS} outputs are enabled following \overline{RASIN} , and \overline{CAS} is inhibited. This refreshes the same row in all four banks. The refresh counter increments when either \overline{RASIN} or RFSH goes low-to-high after a refresh. RF I/O goes low when the count is 127, 255, or 511, as set by End-of-Count (see Table 3), with \overline{RASIN} and RFSH low. To reset the counter to all zeroes, RF I/O is set low through an external open-collector driver.

During refresh, \overline{RASIN} and RFSH must be skewed transitioning low such that the refresh address is valid on the address outputs of the controller before the \overline{RAS} outputs go low. The amount of time that RFSH should go low before \overline{RASIN} does depends on the capacitive loading of the address and \overline{RAS} lines. For the load specified in the switching characteristics of this data sheet, 10ns is sufficient. Refer to Figure 2.

To perform externally controlled burst refresh, \overline{RASIN} is toggled while RFSH is held low. The refresh counter increments with \overline{RASIN} going low to high, so that the DRAM rows are refreshed in succession by \overline{RASIN} going high to low.



* INDICATES DYNAMIC RAM PARAMETERS

END OF COUNT LOW IF n=127, 255, 511

COUNTER RESET INPUT FROM OPEN COLLECTOR

FIGURE 2. External Control Refresh Cycle (Mode 0)

Mode 1 — Automatic Forced Refresh

In Mode 1, the R/\overline{C} (RFCK) pin becomes RFCK (refresh cycle clock), instead of R/\overline{C} , and \overline{CAS} remains high. If RFCK is kept permanently high, then whenever M2 (RFSH) goes low, an externally controlled refresh will occur and all RAS outputs will follow RASIN, strobing the refresh counter contents to the DRAMs. The RF I/O pin will always output high, but when set low externally through an open-collector driver, the refresh counter resets as normal. This externally controlled method may be preferred when operating in the Automatic Access mode (Mode 5), where hidden or forced refreshing is undesirable, but refreshing is still necessary.

If RFCK is an input clock signal, one (and only one) refresh cycle must take place every RFCK cycle. Refer to Figure 9. If a hidden refresh does not occur while RFCK is high, in Mode 5, then RF I/O (Refresh Request) goes low immediately after RFCK goes low, indicating to the system that a forced refresh is requested. The system must allow a forced refresh to take place while RFCK is low (refer to Figure 3). The Refresh Request signal on RF I/O may be connected to a Hold or Bus Request input to the system. The system acknowledges the Hold or Bus Request when ready, and outputs Hold Acknowledge or Bus Request Acknowledge. If this is connected to the M2 (RFSH) pin, a forced refresh cycle will be initiated by the DP8409, and RAS will be internally generated on all four RAS outputs, to strobe the refresh counter contents on the address outputs into all the DRAMs. An external RAS Generator Clock

(RGCK) is required for this function. It is fed to the CASIN (RGCK) pin, and may be up to 10MHz. Whenever M2 goes low (inducing a forced refresh), RAS remains high for one to two periods of RGCK, depending on when M2 goes low relative to the high-to-low triggering edge of RGCK; RAS then goes low for two periods, performing a refresh on all banks. In order to obtain the minimum delay from M2 going low to RAS going low, M2 should go low t_{RFSRG} before the next falling edge of RGCK. The Refresh Request on RF I/O is terminated as RAS begins, so that by the time the system has acknowledged the request and disabled its Acknowledge, (i.e., M2 goes high), Refresh RAS will have ended, and normal operations can begin again in the Automatic Access mode (Mode 5). If it is desired that Refresh RAS end in less than 2 periods of RGCK from the time RAS went low, then M2 may be high earlier than t_{RQHRF} after RGCK goes low and RAS will go high t_{RFRH} after M2, if CS is low. If CS is high, the RAS will go high impedance high after 25ns after M2 goes high.

To allow the forced refresh, the system will have been inactive for about 4 periods of RGCK, which can be as fast as 400ns every RFCK cycle. To guarantee a refresh of 128 rows every 2ms, a period of up to 16µs is required for RFCK. In other words, the system may be down for as little as 400ns every 16µs, or 2.5% of the time. Although this is not excessive, it may be preferable to perform a Hidden Refresh each RFCK cycle, which is allowed while still in the Auto-Access mode, (Mode 5).

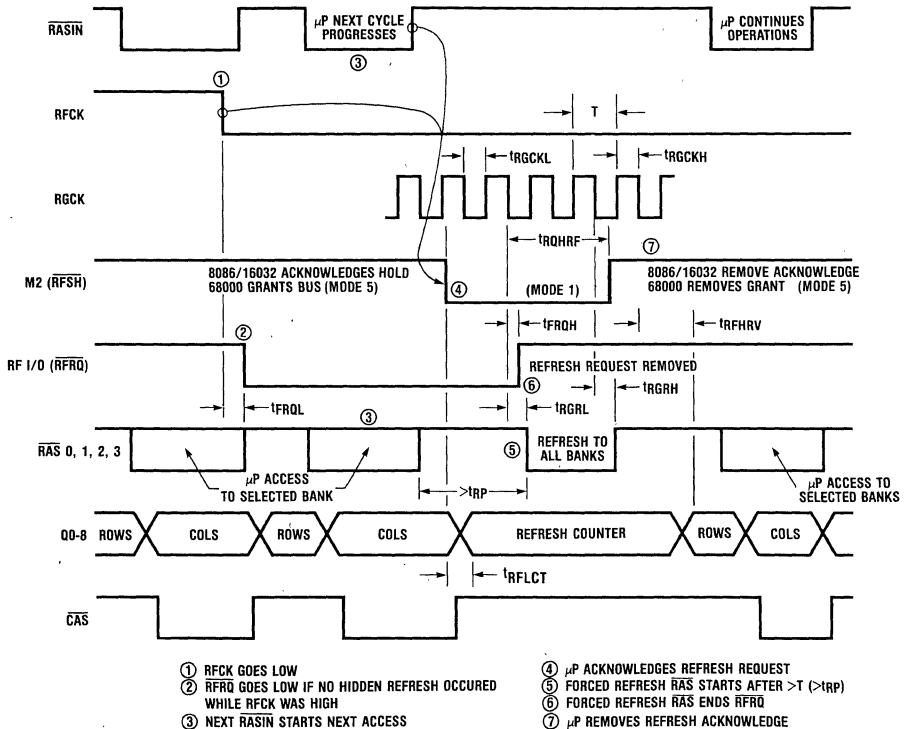


FIGURE 3. DP8409 Performing a Forced Refresh (Mode 5→1→5) with Various Microprocessors

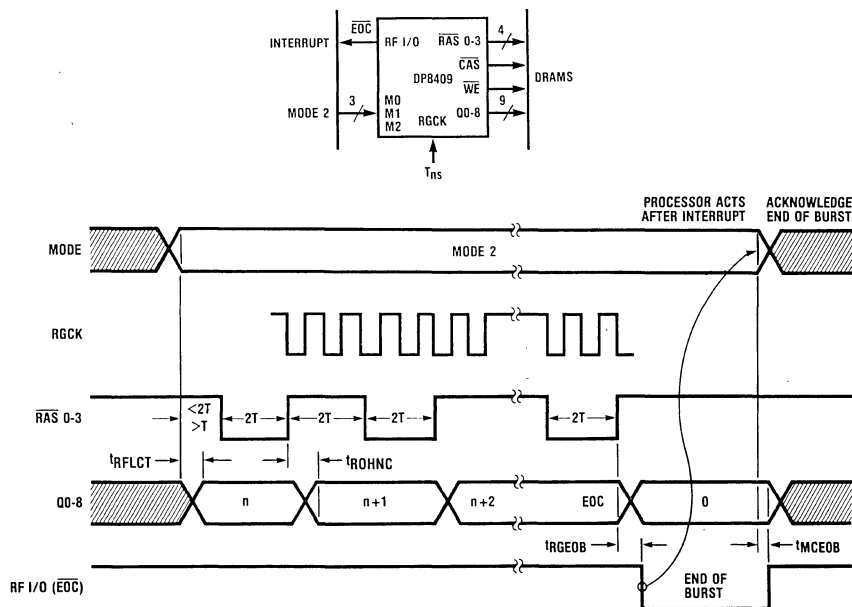


FIGURE 4. Auto-Burst Mode, Mode 2

Mode 2 — Automatic Burst Refresh

This mode is normally used before and/or after a DMA operation to ensure that all rows remain refreshed, provided the DMA transfer takes less than 2ms (see Figure 4). When the DP8409 enters this mode, CASIN (RGCK) becomes the RAS Generator Clock (RGCK), and RASIN is disabled. CAS remains high, and RF I/O goes low when the refresh counter has reached the selected End-of-Count and the last RAS has ended. RF I/O then remains low until the Auto-Burst Refresh mode is terminated. RF I/O can therefore be used as an interrupt to indicate the End-of-Burst condition.

The signal on all four RAS outputs is just a divide-by-four of RGCK; in other words, if RGCK has a 100ns period, RAS is high and low for 200ns each cycle. The refresh counter increments at the end of each RAS, starting from the count it contained when the mode was entered. If this was zero, then for a RGCK with a 100ns period with End-of Count set to 127, RF I/O will go low after $128 \times 0.4 \mu s$, or $51.2 \mu s$. During this time, the system may be performing operations that do not involve DRAM. If all rows need to be burst refreshed, the refresh counter may be cleared by setting RF I/O low externally before the burst begins.

Burst-mode refreshing is also useful when powering down systems for long periods of time, but with data retention still required while the DRAMs are in standby. To maintain valid refreshing, power can be applied to the DP8409 (set to Mode 2), causing it to perform a complete burst refresh. When end-of-burst occurs (after $26 \mu s$), power can then be removed from the DP8409 for 2ms, consuming an average power of 1.3% of normal operating power. No control signal glitches occur when switching power to the DP8409.

Mode 3a — All-RAS Automatic Write

Mode 3a is useful at system initialization, when the memory is being cleared (i.e., with all-zeroes in the data field and the corresponding check bits for error detection and correction). This requires writing the same data to each location of memory (every row of each column of each bank). All RAS outputs are activated, as in refresh, and so are CAS and WE. To write to all four banks simultaneously, every row is strobed in each column, in sequence, until data has been written to all locations.

To select this mode, B1 and B0 must have previously been set to 00, 01, or 10 in Mode 7, depending on the DRAM size. For example, for 16k DRAMs, B1 and B0 are 00. For 64k DRAMs, B1 and B0 are 01, so that for the configuration of Figure 1b, the 8 refresh counter bits are strobed by RAS into the 7 row addresses and the ninth column address. After this Automatic-Write process, B1 and B0 must be set again in Mode 7 to 00 to set End-of-Count to 127. For the configuration of Figure 1c, B1 and B0 set to 01 will work for Automatic-Write and End-of-Count equals 255.

In this mode, R/C is disabled, WE is permanently enabled low, and CASIN (RGCK) becomes RGCK. RF I/O goes low whenever the refresh counter is 127, 255, or 511 (as set by End-of-Count in Mode 7), and the RAS outputs are active.

Referring to Figure 5a, an external 8-bit counter (for 64k DRAMs) with TRI-STATE outputs is required and must be connected to the column address inputs. It is enabled only during this mode, and is clocked from RF I/O. The DP8409 refresh counter is used to address the rows, and the column address is supplied by the external counter. Every row for each column address is written to in all four banks. At the End-of-Count RF I/O goes low, which clocks the external counter.

Therefore, for each column address, the refresh counter first outputs row-0 to the address bus and all four RAS outputs strobe this row address into the DRAMs (see Figure 5b). A minimum of 30ns after RAS goes low ($t_{RAH} = 30ns$), the refresh counter is disabled and the column address input latch is enabled onto the address bus. About 14ns after the column address is valid, CAS goes low ($t_{ASC} = +14ns$), strobing the column address into the DRAMs. When RAS and CAS go high the refresh counter increments to the next row and the cycle repeats. Since WE is kept low in this mode, the data at DI (input data) of the DRAMs is written into each row of the latched column. During each cycle RAS is high for two periods of RGCK and low for two periods, giving a total write-cycle time of 400ns minimum, which is adequate for most 16k and 64k DRAMs. On the last row of a column, RF I/O increments the external counter to the next column address.

At the end of the last column address, an interrupt is generated from the external counter to let the system know that initialization has been completed. During the entire initialization time, the system can be performing other initialization functions. This approach to memory initialization is both automatic and fast. For instance, if four banks of 64k DRAMs are used, and RGCK is 100 ns, a write cycle to the same location in all four banks takes 400 ns, so the total time taken in initializing the 64k DRAMs is $65k \times 400 ns$ or 26 ms. When the system receives the interrupt, the external counter must be permanently disabled. ADS and CS are interfaced by the system, and the DP8409 mode is changed. The interrupt must then be disabled.

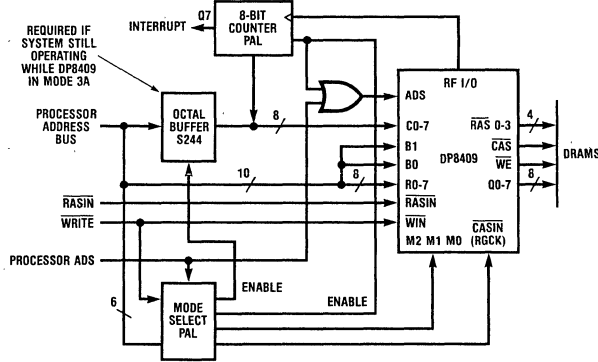


FIGURE 5a. DP8409 Extra Circuitry Required for All-RAS Auto Write Mode, Mode 3a

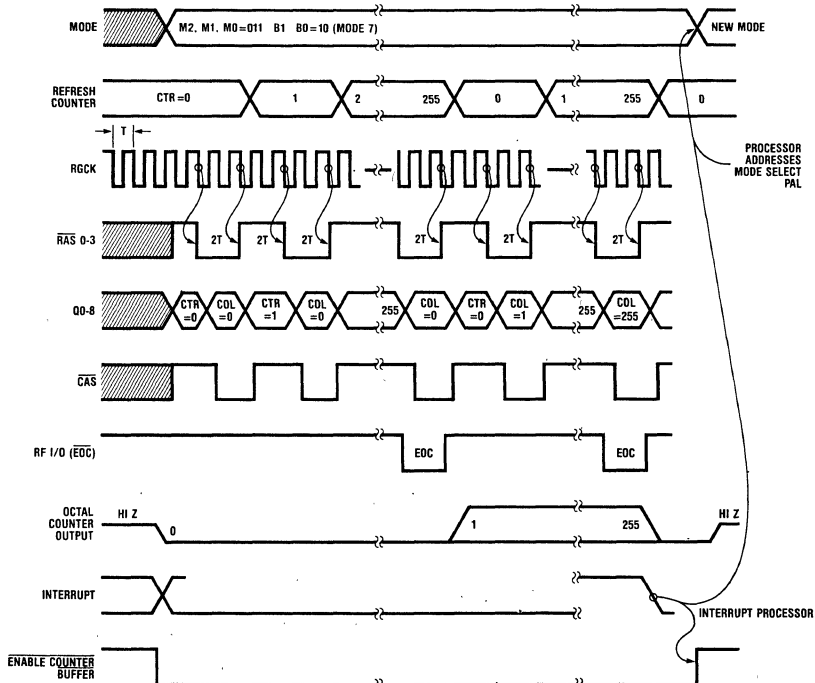


FIGURE 5b. DP8409 All-RAS Auto Write Mode, Mode 3a, Timing Waveform

Mode 3b — Externally Controlled All- $\overline{\text{RAS}}$ Write

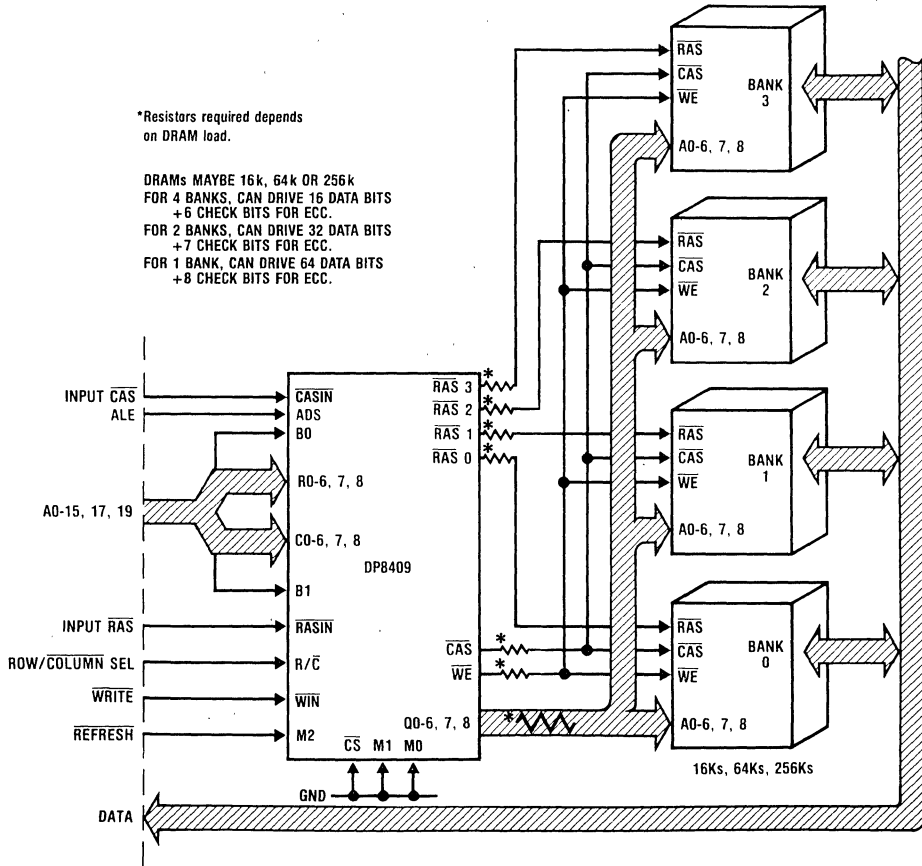
To select this mode, B1 and B0 must first have been set to 11 in Mode 7. This mode is useful at system initialization, but under processor control. The memory address is provided by the processor, which also performs the incrementing. All four $\overline{\text{RAS}}$ outputs follow $\overline{\text{RASIN}}$ (supplied by the processor), strobing the row address into the DRAMs. $\overline{\text{R/C}}$ can now go low, while $\overline{\text{CASIN}}$ may be used to control $\overline{\text{CAS}}$ (as in the Externally Controlled Access mode), so that $\overline{\text{CAS}}$ strobes the column address contents into the DRAMs. At this time $\overline{\text{WE}}$ should be low, causing the data to be written into all four banks of DRAMs. At the end of the write cycle, the input address is incremented and latched by the DP8409 for the next write cycle. This method is slower than Mode 3a since the processor must perform the incrementing and accessing. Thus the processor is occupied during RAM initialization, and is not free for other initialization operations. However, initialization sequence timing is under system control, which may provide some system advantage.

Mode 4 — Externally Controlled Access

This mode facilitates externally controlling all access-timing parameters associated with the DRAMs. The application of modes 0 and 4 are shown in Figure 6.

Output Address Selection

Refer to Figure 7a. With M2 ($\overline{\text{RFSH}}$) and $\overline{\text{R/C}}$ high, the row address latch contents are transferred to the multiplexed address bus output Q0-Q8, provided $\overline{\text{CS}}$ is set low. The column address latch contents are output after $\overline{\text{R/C}}$ goes low. $\overline{\text{RASIN}}$ can go low after the row addresses have been set up on Q0-Q8. This selects one of the $\overline{\text{RAS}}$ outputs, strobing the row address on the Q outputs into the desired bank of memory. After the row-address hold-time of the DRAMs, $\overline{\text{R/C}}$ can go low so that about 40 ns later column addresses appear on the Q outputs.



7

FIGURE 6. Typical Application of DP8409 Using External Control Access and Refresh in Modes 0 and 4

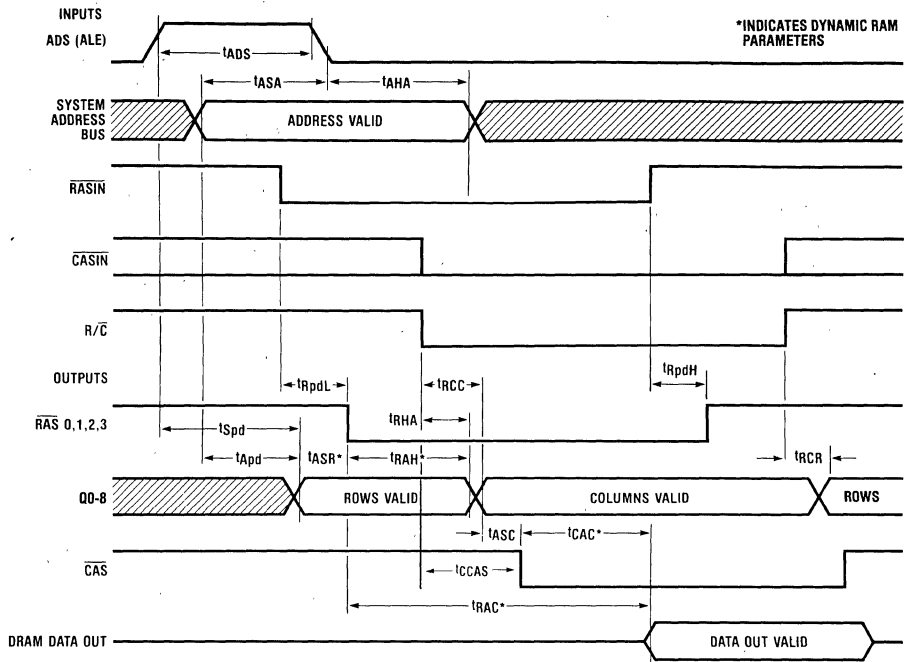


FIGURE 7a. Read Cycle Timing (MODE 4)

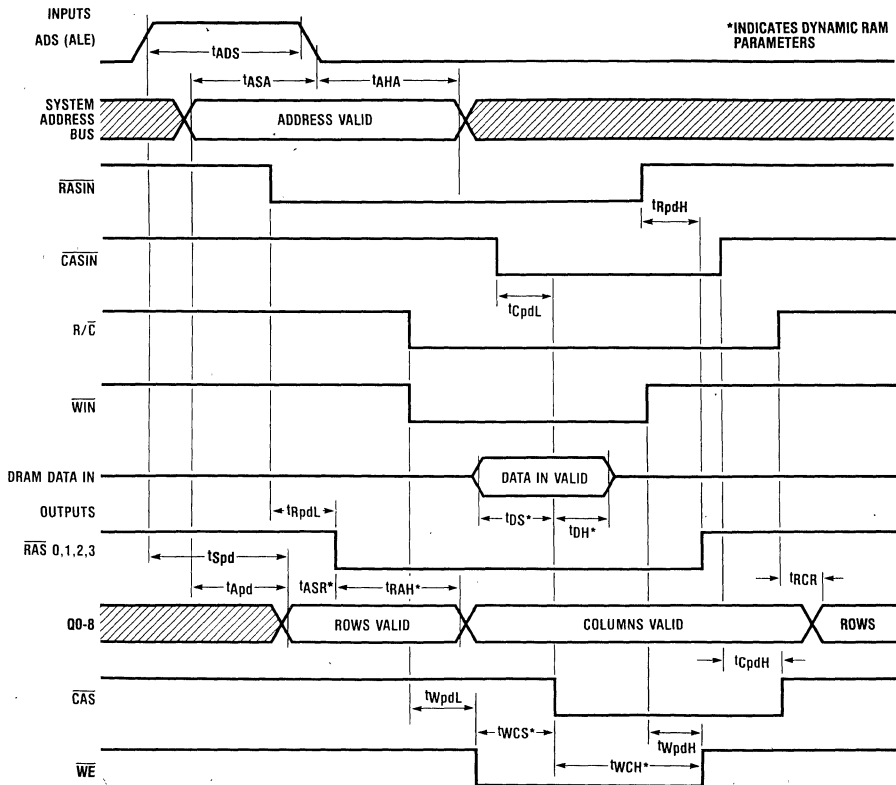


FIGURE 7b. Write Cycle Timing (Mode 4)

Automatic CAS Generation

In a normal memory access cycle $\overline{\text{CAS}}$ can be derived from inputs CASIN or R/C . If CASIN is high, then R/C going low switches the address output drivers from rows to columns. CASIN then going low causes CAS to go low approximately 40 ns later, allowing CAS to occur at a predictable time (see Figure 7b). If CASIN is low when R/C goes low, $\overline{\text{CAS}}$ will be automatically generated, following the row to column transition by about 20 ns (see Figure 7a). Most DRAMs have a column address set-up time before $\overline{\text{CAS}}$ (t_{ASC}) of 0 ns or -10 ns. In other words, a t_{ASC} greater than 0 ns is safe.

Fast Memory Access

AC parameters t_{DIF1} , t_{DIF2} may be used to determine the minimum delays required between $\overline{\text{RASIN}}$, R/C , and CASIN (see Application Brief 9; "Fastest DRAM Access Mode").

Mode 5 — Automatic Access with Hidden Refresh

The Auto Access with Hidden Refresh mode has two advantages over the Externally Controlled Access mode, due to the fact that all outputs except $\overline{\text{WE}}$ are initiated from $\overline{\text{RASIN}}$. First, inputs R/C and CASIN are unnecessary and can be used for other functions (see Refreshing, below). Secondly, because the output control signals are derived internally from one input signal ($\overline{\text{RASIN}}$), timing-skew problems are reduced, thereby reducing memory access time substantially or allowing use of slower DRAMs. The automatic access features of Mode 5 (and Mode 6) of the DP8409 make DRAM accessing appear essentially "static".

Automatic Access Control

The major disadvantage of DRAMs compared to static RAMs is the complex timing involved. First, a $\overline{\text{RAS}}$ must occur with the row address previously set up on the multiplexed address bus. After the row address has been held for t_{RAH} , (the Row-Address hold-time of the DRAM), the column address is set up and then $\overline{\text{CAS}}$ occurs. This is all performed automatically by the DP8409 in this mode.

Provided the input address is valid as ADS goes low, $\overline{\text{RASIN}}$ can go low any time after ADS . This is because the selected $\overline{\text{RAS}}$ occurs typically 27 ns later, by which time the row address is already valid on the address output of the DP8409. The Address Set-Up time (t_{ASR}), is 0 ns on most DRAMs. The DP8409 in this mode (with ADS and $\overline{\text{RASIN}}$ edges simultaneously applied) produces a minimum t_{ASR} of 0 ns. This is true provided the input address was valid t_{ASA} before ADS went low (see Figure 8a).

Next, the row address is disabled after t_{RAH} (30 ns minimum); in most DRAMs, t_{RAH} minimum is less than 30 ns. The column address is then set up and t_{ASC} later, $\overline{\text{CAS}}$ occurs. The only other control input required is $\overline{\text{WIN}}$. When a write cycle is required, $\overline{\text{WIN}}$ must go low at least 30 ns before $\overline{\text{CAS}}$ is output low.

This gives a total typical delay from: input address valid to $\overline{\text{RASIN}}$ (15 ns); to $\overline{\text{RAS}}$ (27 ns); to rows held (50 ns); to columns valid (25 ns); to $\overline{\text{CAS}}$ (23 ns) = 140 ns (that is, 125 ns from $\overline{\text{RASIN}}$). All of these typical figures are for heavy capacitive loading, of approximately 88 DRAMs.

This mode is therefore extremely fast. The external timing is greatly simplified for the memory system designer: the only system signal required is $\overline{\text{RASIN}}$.

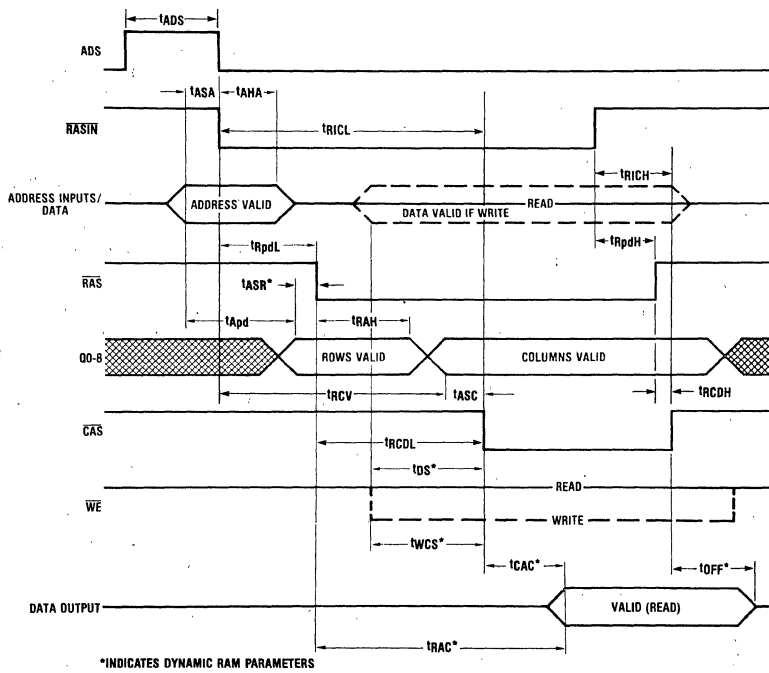
Refreshing

Because R/C and $\overline{\text{CASIN}}$ are not used in this mode, R/C becomes $\overline{\text{RFCK}}$ (refresh clock) and CASIN becomes $\overline{\text{RGCK}}$ ($\overline{\text{RAS}}$ generator clock). With these two signals it is possible to perform refreshing without extra ICs, and without holding up the processor.

One refresh cycle must occur during each refresh clock period and then the refresh address must be incremented to the next refresh cycle. As long as 128 rows are refreshed every 2 ms (one row every 16 μs), all 16k and 64k DRAMs will be correctly refreshed. The cycle time of $\overline{\text{RFCK}}$ must, therefore, be less than 16 μs . $\overline{\text{RFCK}}$ going high sets an internal refresh-request flip-flop. First the DP8409 will attempt to perform a hidden refresh so that the system throughput will not be affected. If, during the time $\overline{\text{RFCK}}$ is high, $\overline{\text{CS}}$ on the DP8409 goes high and $\overline{\text{RASIN}}$ occurs, a hidden refresh will occur. In this case, $\overline{\text{RASIN}}$ should be considered a common read/write strobe. In other words, if the processor is accessing elsewhere (other than the DRAMs) while $\overline{\text{RFCK}}$ is high, the DP8409 will perform a refresh. The refresh counter is enabled to the address outputs whenever $\overline{\text{CS}}$ goes high with $\overline{\text{RFCK}}$ high, and all $\overline{\text{RAS}}$ outputs follow $\overline{\text{RASIN}}$. If a hidden refresh is taking place as $\overline{\text{RFCK}}$ goes low, the refresh continues. At the start of the hidden refresh, the refresh-request flip-flop is reset so no further refresh can occur until the next $\overline{\text{RFCK}}$ period starts with the positive-going edge of $\overline{\text{RFCK}}$. Refer to Figure 9.

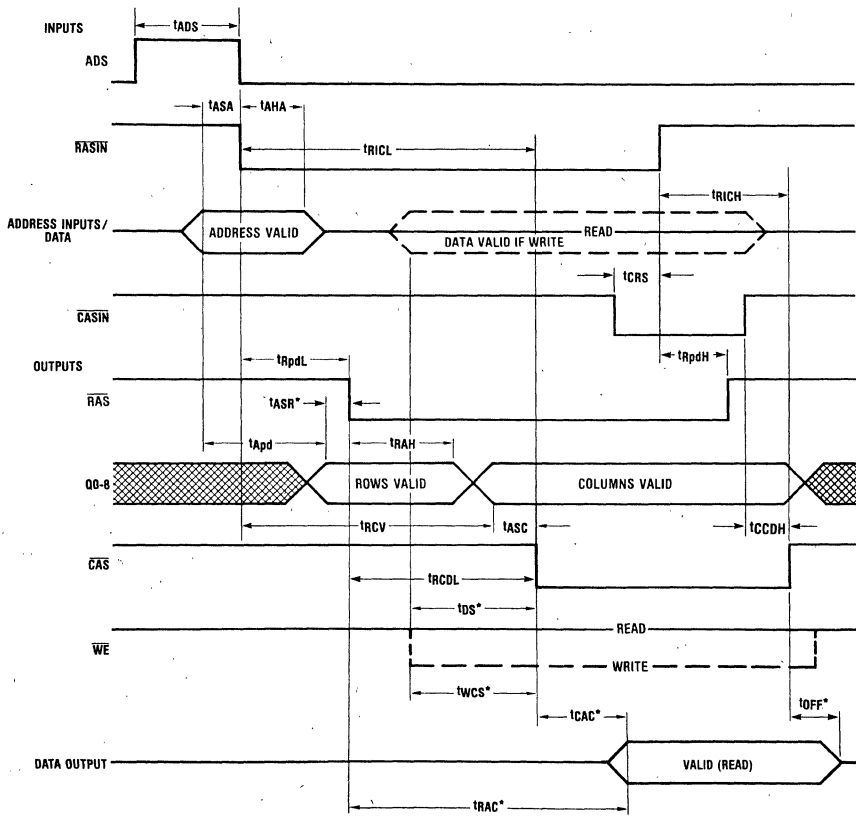
To determine the probability of a Hidden Refresh occurring, assume each system cycle takes 400 ns and $\overline{\text{RFCK}}$ is high for 8 μs , then the system has 20 chances to not select the DP8409. If during this time a hidden refresh did not occur, then the DP8409 forces a refresh while $\overline{\text{RFCK}}$ is low, but the system chooses when the refresh takes place. After $\overline{\text{RFCK}}$ goes low, (and the internal-refresh flip-flop has not been reset), $\overline{\text{RF}}$ I/O goes low indicating that a refresh is requested to the system. Only when the system acknowledges this request by setting M2 ($\overline{\text{RFSH}}$) low does the DP8409 initiate a forced refresh (which is performed automatically). Refer to Mode 1, and Figure 3. The internal refresh request flip-flop is then reset.

Figure 9 illustrates the refresh alternatives in Mode 5. If a hidden refresh has occurred and $\overline{\text{CS}}$ again goes high before $\overline{\text{RFCK}}$ goes low, the chip is deselected. All the control signals go high-impedance high (logic "1") and the address outputs go TRI-STATE until $\overline{\text{CS}}$ again goes low. This mode (combined with Mode 1) allows very fast access, and automatic refreshing (possibly not even slowing down the system), with no extra ICs. Careful system design can, and should, provide a higher probability of hidden refresh occurring. The duty cycle of $\overline{\text{RFCK}}$ need not be 50-percent; in fact, the low-time should be designed to be a minimum. This is determined by the worst-case time (required by the system) to respond to the DP8409's forced-refresh request.



*INDICATES DYNAMIC RAM PARAMETERS

FIGURE 8a. Modes 5, 6 Timing ($\overline{\text{CASIN}}$ High in Mode 6)



*INDICATES DYNAMIC RAM PARAMETERS

FIGURE 8b. Mode 6 Timing, Extended $\overline{\text{CAS}}$

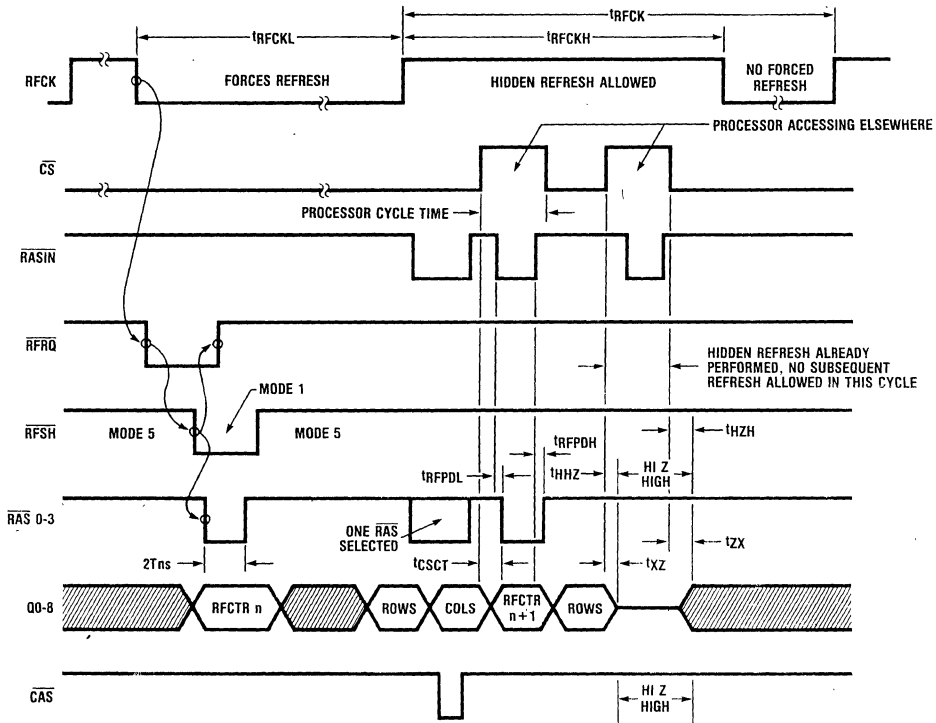
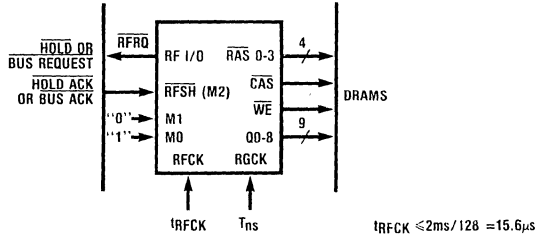


FIGURE 9. Hidden Refreshing (Mode 5) and Forced Refreshing (Mode 1) Timing

Table 2. Memory Bank Decode

Bank Select (Strobed by ADS)		Enabled \overline{RAS}_n
B1	B0	
0	0	\overline{RAS}_0
0	1	\overline{RAS}_1
1	0	\overline{RAS}_2
1	1	\overline{RAS}_3

Note that \overline{RASIN} going low earlier than t_{CSRL} after \overline{CS} goes low may result in the DP8409 interpreting the \overline{RASIN} as a hidden refresh \overline{RASIN} if no hidden refresh has occurred in the current RFCK cycle. In this case, all \overline{RAS} outputs would go low for a short time. Thus, it is suggested that when using Mode 5, \overline{RASIN} should be held high until t_{CSRL} after \overline{CS} goes low if a refresh is not intended. Similarly, \overline{CS} should be held low for a minimum of t_{CSRL} after \overline{RASIN} returns high when ending the access in Mode 5.

Mode 6 — Fast Automatic Access

The Fast Access mode is similar to Mode 5, but has a faster t_{RAH} of 20ns, minimum. It therefore can only be used with fast 16k or 64k DRAMs (which have a t_{RAH} of 10ns to 15ns) in applications requiring fast access times; \overline{RASIN} to \overline{CAS} is typically 105ns.

In this mode, the R/\overline{C} (RFCK) pin is not used, but \overline{CASIN} (RGCK) is used as \overline{CASIN} to allow an extended \overline{CAS} after \overline{RAS} has already terminated. Refer to Figure 8b. This is desirable with fast cycle-times where \overline{RAS} has to be terminated as soon as possible before the next \overline{RAS}

begins (to meet the precharge time, or t_{RP} , requirements of the DRAM). \overline{CAS} may then be held low by \overline{CASIN} to extend the data output valid time from the DRAM to allow the system to read the data. \overline{CASIN} subsequently going high ends \overline{CAS} . If this extended \overline{CAS} is not required, \overline{CASIN} should be set high in Mode 6.

There is no internal refresh-request flip-flop in this mode, so any refreshing required must be done by entering Mode 0 or Mode 2.

Mode 7 — Set End-of-Count

The End-of-Count can be externally selected in Mode 7, using ADS to strobe in the respective value of B1 and B0 (see Table 3). With B1 and B0 the same \overline{EOC} is 127; with B1=0 and B0=1, \overline{EOC} is 255; and with B1=1 and B0=0, \overline{EOC} is 511. This selected value of \overline{EOC} will be used until the next Mode 7 selection. At power-up the \overline{EOC} is automatically set to 127 (B1 and B0 set to 11).

Table 3. Mode 7

Bank Select (Strobed by ADS)		End of Count Selected
B1	B0	
0	0	127
0	1	255
1	0	511
1	1	127

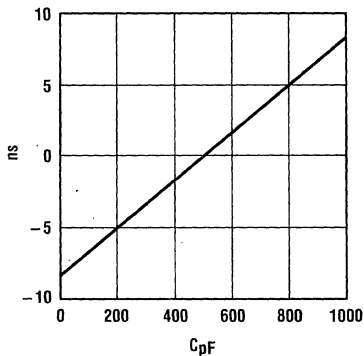


FIGURE 10. Change in Propagation Delay vs. Loading Capacitance Relative to a 500pF Load

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Storage Temperature Range	-65°C to +150°C
Input Voltage	5.5V
Output Current	150mA
Lead Temperature (Soldering, 10 seconds)	300°C

*Derate cavity package 23.6mW/°C above 25°C; derate molded package 22.7mW/°C above 25°C.

Maximum Power Dissipation* at 25°C

Cavity Package	3542mW
Molded Package	2833mW

Operating Conditions

	Min	Max	Units
V_{CC} Supply Voltage	4.75	5.25	V
T_A Ambient Temperature	0	+70	°C

Electrical Characteristics $V_{CC} = 5.0V \pm 5\%$, $0^\circ C \leq T_A \leq 70^\circ C$ unless otherwise noted (Notes 2, 6)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_C	Input Clamp Voltage	$V_{CC} = \text{Min.}, I_C = -12\text{mA}$		-0.8	-1.2	V
I_{IH1}	Input High Current for ADS, R/\bar{C} only	$V_{IN} = 2.5V$		2.0	100	μA
I_{IH2}	Input High Current for All Other Inputs*	$V_{IN} = 2.5V$		1.0	50	μA
$I_{I\text{ RSI}}$	Output Load Current for RF I/O	$V_{IN} = 0.5V$, Output High		-1.5	-2.5	mA
$I_{I\text{ CTL}}$	Output Load Current for $\overline{\text{RAS}}$, $\overline{\text{CAS}}$, $\overline{\text{WE}}$	$V_{IN} = 0.5V$, Chip Deselect		-1.5	-2.5	mA
I_{IL1}	Input Low Current for ADS, R/\bar{C} only	$V_{IN} = 0.5V$		-0.1	-1.0	mA
I_{IL2}	Input Low Current for All Other Inputs*	$V_{IN} = 0.5V$		-0.05	-0.5	mA
V_{IL}	Input Low Threshold				0.8	V
V_{IH}	Input High Threshold		2.0			V
V_{OL1}	Output Low Voltage*	$I_{OL} = 20\text{mA}$		0.3	0.5	V
V_{OL2}	Output Low Voltage for RF I/O	$I_{OL} = 10\text{mA}$		0.3	0.5	V
V_{OH1}	Output High Voltage*	$I_{OH} = -1\text{mA}$	2.4	3.5		V
V_{OH2}	Output High Voltage for RF I/O	$I_{OH} = -100\mu\text{A}$	2.4	3.5		V
I_{1D}	Output High Drive Current*	$V_{OUT} = 0.8V$ (Note 3)		-200		mA
I_{0D}	Output Low Drive Current*	$V_{OUT} = 2.7V$ (Note 3)		200		mA
I_{0Z}	TRI-STATE Output Current (Address Outputs)	$0.4V \leq V_{OUT} \leq 2.7V$, $C_S = 2.0V$, Mode 4	-50	1.0	50	μA
I_{CC}	Supply Current	$V_{CC} = \text{Max.}$		250	325	mA

*Except RF I/O Output.

Switching Characteristics: DP8409/DP8409-3 $V_{CC} = 5.0V \pm 5\%$, $0^\circ C \leq T_A \leq 70^\circ C$ unless otherwise noted (Notes 2, 4, 5). The output load capacitance is typical for 4 banks of 22 DRAMs each or 88 DRAMs including trace capacitance. These values are: Q0-Q8, $C_L = 500\text{pF}$; $\overline{\text{RAS0}}-\overline{\text{RAS3}}$, $C_L = 150\text{pF}$; $\overline{\text{WE}}$, $C_L = 500\text{pF}$; $\overline{\text{CAS}}$, $C_L = 600\text{pF}$, unless otherwise noted. See Figure 11 for test load. Switches S1 and S2 are closed unless otherwise noted, and R1 and R2 are 4.7k Ω unless otherwise noted. Maximum propagation delays are specified with all outputs switching.

Symbol	Access Parameter	Conditions	8409			8409-3			Units
			Min	Typ	Max	Min	Typ	Max	
t_{RICL}	$\overline{\text{RAS}}/\overline{\text{CAS}}$ Output Delay (Mode 5)	Figure 8a	95	125	160	95	125	185	ns
t_{RICL}	$\overline{\text{RAS}}/\overline{\text{CAS}}$ Output Delay (Mode 6)	Figures 8a, 8b	80	105	140	80	105	160	ns
t_{RICH}	$\overline{\text{RAS}}/\overline{\text{CAS}}$ Output Delay (Mode 5)	Figure 8a	40	48	60	40	48	70	ns
t_{RICH}	$\overline{\text{RAS}}/\overline{\text{CAS}}$ Output Delay (Mode 6)	Figures 8a, 8b	50	63	80	50	63	95	ns
t_{RCDL}	$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Output Delay (Mode 5)	Figure 8a		98	125		98	145	ns
t_{RCDL}	$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Output Delay (Mode 6)	Figures 8a, 8b		78	105		78	120	ns
t_{RCDH}	$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Output Delay (Mode 5)	Figure 8a		27	40		27	40	ns
t_{RCDH}	$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Output Delay (Mode 6)	Figure 8a		40	65		40	65	ns
t_{CCDH}	$\overline{\text{CAS}}/\overline{\text{CAS}}$ Output Delay (Mode 6)	Figure 8b	40	54	70	40	54	80	ns
t_{RAH}	Row Address Hold Time (Mode 5)	Figure 8a	30			30			ns
t_{RAH}	Row Address Hold Time (Mode 6)	Figures 8a, 8b	20			20			ns
t_{ASC}	Column Address Setup Time (Mode 5)	Figure 8a	8			8			ns
t_{ASC}	Column Address Setup Time (Mode 6)	Figures 8a, 8b	6			6			ns
t_{RCV}	$\overline{\text{RAS}}/\overline{\text{CAS}}$ to Column Address Valid (Mode 5)	Figure 8a		90	120		90	140	ns



Switching Characteristics (Cont'd)

Symbol	Access Parameter	Conditions	8409			8409 - 3			Units
			Min	Typ	Max	Min	Typ	Max	
t_{RCV}	RASIN to Column Address Valid (Mode 6)	Figures 8a, 8b		75	105		75	120	ns
t_{RPDL}	RASIN to RAS Delay	Figures 7a, 7b, 8a, 8b	20	27	35	20	27	40	ns
t_{RPDH}	RASIN to RAS Delay	Figures 7a, 7b, 8a, 8b	15	23	32	15	23	37	ns
t_{APDL}	Address Input to Output Low Delay	Figures 7a, 7b, 8a, 8b		25	40		25	46	ns
t_{APDH}	Address Input to Output High Delay	Figures 7a, 7b, 8a, 8b		25	40		25	46	ns
t_{SPDL}	Address Strobe to Address Output Low	Figures 7a, 7b		40	60		40	70	ns
t_{SPDH}	Address Strobe to Address Output High	Figures 7a, 7b		40	60		40	70	ns
t_{ASA}	Address Set-up Time to ADS	Figures 7a, 7b, 8a, 8b	15			15			ns
t_{AHA}	Address Hold Time from ADS	Figures 7a, 7b, 8a, 8b	15			15			ns
t_{ADS}	Address Strobe Pulse Width	Figures 7a, 7b, 8a, 8b	30			30			ns
t_{WPDL}	WIN to WE Output Delay	Figure 7b	15	25	30	15	25	35	ns
t_{WPDH}	WIN to WE Output Delay	Figure 7b	15	30	60	15	30	70	ns
t_{CRS}	CASIN Set-up Time to RASIN High (Mode 6)	Figure 8b	35			35			ns
t_{CPDL}	CASIN to CAS Delay (R/C low in Mode 4)	Figure 7b	32	41	68	32	41	77	ns
t_{CPDH}	CASIN to CAS Delay (R/C low in Mode 4)	Figure 7b	25	39	50	25	39	60	ns
t_{RCC}	Column Select to Column Address Valid	Figure 7a		40	58		40	67	ns
t_{RCR}	Row Select to Row Address Valid	Figures 7a, 7b		40	58		40	67	ns
t_{RHA}	Row Address Held from Column Select	Figure 7a	10			10			ns
t_{CCAS}	R/C Low to CAS Low (Mode 4 Auto CAS)	Figure 7a		65	90				ns
t_{DIF1}	Maximum ($t_{RPDL} - t_{RHA}$)	See Mode 4 description				13		18	ns
t_{DIF2}	Maximum ($t_{RCC} - t_{CPDL}$)	See Mode 4 description				13		18	ns
Refresh Parameter									
t_{RC}	Refresh Cycle Period	Figure 2	100			100			ns
$t_{RASINL,H}$	Pulse Width of RASIN during Refresh	Figure 2	50			50			ns
t_{RFPDL}	RASIN to RAS Delay during Refresh	Figures 2, 9	35	50	70	35	50	80	ns
t_{RFPDH}	RASIN to RAS Delay during Refresh	Figures 2, 9	30	40	55	30	40	65	ns
t_{RFLCT}	RFSH Low to Counter Address Valid	CS = X, Figures 2,3,4		47	60		47	70	ns
t_{RFHRV}	RFSH High to Row Address Valid	Figures 2, 3		45	60		45	70	ns
t_{ROHNC}	RAS High to New Count Valid	Figures 2, 4		30	55		30	55	ns
t_{RLEOC}	RASIN Low to End-of-Count Low	$C_L = 50\text{pF}$, Figure 2			80			80	ns
t_{RHEOC}	RASIN High to End-of-Count High	$C_L = 50\text{pF}$, Figure 2			80			80	ns
t_{RGEOB}	RGCK Low to End-of-Burst Low	$C_L = 50\text{pF}$, Figure 4			95			95	ns
t_{MCEOB}	Mode Change to End-of-Burst High	$C_L = 50\text{pF}$, Figure 4			75			75	ns
t_{RST}	Counter Reset Pulse Width	Figure 2	70			70			ns
t_{CTL}	RF I/O Low to Counter Outputs All Low	Figure 2			100			100	ns
$t_{RFCKL,H}$	Minimum Pulse Width of RFCK	Figure 9	100			100			ns
T	Period of RAS Generator Clock	Figure 3	100			100			ns
t_{RGCKL}	Minimum Pulse Width Low of RGCK	Figure 3	35			40			ns
t_{RGCKH}	Minimum Pulse Width High of RGCK	Figure 3	35			40			ns
t_{FRQL}	RFCK Low to Forced RFRQ Low	$C_L = 50\text{pF}$, Figure 3		20	30		20	30	ns

Switching Characteristics (Cont'd)

Symbol	Refresh Parameter	Conditions	8409			8409 - 3			Units
			Min	Typ	Max	Min	Typ	Max	
t _{FRQH}	RGCK Low to Forced RFRQ High	C _L = 50pF, Figure 3		50	75		50	75	ns
t _{RGRL}	RGCK Low to RAS Low	Figure 3	50	65	95	50	65	95	ns
t _{RGRRH}	RGCK Low to RAS High	Figure 3	40	60	85	40	60	85	ns
t _{RQHRF}	RFSH Hold Time from RFSH RQST (RF I/O)	Figure 3	2T			2T			ns
t _{RFRH}	RFSH High to RAS High (ending forced RFSH)	See Mode 1 Descrip.	55	80	110	55	80	125	ns
t _{RFSRG}	RFSH Low Set-up to RGCK Low (Mode 1)	See Mode 1 Descrip.	35			40			ns
t _{CSCST}	CS High to RFSH Counter Valid	Figure 9		55	70		55	75	ns
t _{CSRL}	CS Low to Access RASIN Low	See Mode 5 Descrip.	10			15			ns

TRI-STATE Parameter

t _{ZH}	CS Low to Address Output High from Hi-Z	Figures 9, 12 R1 = 3.5k, R2 = 1.5k		35	60		35	60	ns
t _{HZ}	CS High to Address Output Hi-Z from High	C _L = 15pF, Figures 9, 12 R2 = 1k, S1 open		20	40		20	40	ns
t _{ZL}	CS Low to Address Output Low from Hi-Z	Figures 9, 12 R1 = 3.5k, R2 = 1.5k		35	60		35	60	ns
t _{LZ}	CS High to Address Output Hi-Z from Low	C _L = 15pF, Figures 9, 12, R1 = 1k, S2 open		25	50		25	50	ns
t _{HZH}	CS Low to Control Output High from Hi-Z High	Figures 9, 12 R2 = 750Ω, S1 open		50	80		50	80	ns
t _{HHZ}	CS High to Control Output Hi-Z High from High	C _L = 15pF, Figures 9, 12 R2 = 750Ω, S1 open		40	75		40	75	ns
t _{HZL}	CS Low to Control Output Low from Hi-Z High	Figure 12, S1, S2 open		45	75		45	75	ns
t _{LHZ}	CS High to Control Output Hi-Z High from Low	C _L = 15pF, Figure 12, R2 = 750Ω, S1 open		50	80		50	80	ns

Switching Characteristics: DP8409-2 V_{CC} = 5.0V ± 5%, 0°C ≤ T_A ≤ 70°C unless otherwise noted (Notes 2, 4, 5). The output load capacitance is typical for 4 banks of 22 DRAMs each or 88 DRAMs including trace capacitance. These values are: Q0-Q8, C_L = 500pF; RAS0-RAS3, C_L = 150pF; WE, C_L = 500pF; CAS, C_L = 600pF, unless otherwise noted. See Figure 11 for test load. Switches S1 and S2 are closed unless otherwise noted, and R1 and R2 are 4.7kΩ unless otherwise noted. Maximum propagation delays are specified with all outputs switching.

Symbol	Access Parameter	Conditions	8409 - 2			Units
			Min	Typ	Max	
t _{RICL}	RASIN to CAS Output Delay (Mode 5)	Figure 8a	75	100	130	ns
t _{RICL}	RASIN to CAS Output Delay (Mode 6)	Figures 8a, 8b	65	90	115	ns
t _{RICH}	RASIN to CAS Output Delay (Mode 5)	Figure 8a	40	48	60	ns
t _{RICH}	RASIN to CAS Output Delay (Mode 6)	Figures 8a, 8b	50	63	80	ns
t _{RCDL}	RAS to CAS Output Delay (Mode 5)	Figure 8a		75	100	ns
t _{RCDL}	RAS to CAS Output Delay (Mode 6)	Figures 8a, 8b		65	85	ns
t _{RCDH}	RAS to CAS Output Delay (Mode 5)	Figure 8a		27	40	ns
t _{RCDH}	RAS to CAS Output Delay (Mode 6)	Figure 8a		40	65	ns
t _{CCDH}	CASIN to CAS Output Delay (Mode 6)	Figure 8b	40	54	70	ns
t _{RAH}	Row Address Hold Time (Mode 5) (Note 7)	Figure 8a	20			ns

Switching Characteristics (Cont'd)

Symbol	Access Parameter	Conditions	8409 - 2						Units
			Min	Typ	Max	Min	Typ	Max	
t_{RAH}	Row Address Hold Time (Mode 6) (Note 7)	Figures 8a, 8b	12						ns
t_{ASC}	Column Address Setup Time (Mode 5)	Figure 8a	3						ns
t_{ASC}	Column Address Setup Time (Mode 6)	Figures 8a, 8b	3						ns
t_{RCV}	\overline{RASIN} to Column Address Valid (Mode 5)	Figure 8a		80	105				ns
t_{RCV}	\overline{RASIN} to Column Address Valid (Mode 6)	Figures 8a, 8b		70	90				ns
t_{RPDL}	\overline{RASIN} to \overline{RAS} Delay	Figures 7a, 7b, 8a, 8b	20	27	35				ns
t_{RPDH}	\overline{RASIN} to \overline{RAS} Delay	Figures 7a, 7b, 8a, 8b	15	23	32				ns
t_{APDL}	Address Input to Output Low Delay	Figures 7a, 7b, 8a, 8b		25	40				ns
t_{APDH}	Address Input to Output High Delay	Figures 7a, 7b, 8a, 8b		25	40				ns
t_{SPDL}	Address Strobe to Address Output Low	Figures 7a, 7b		40	60				ns
t_{SPDH}	Address Strobe to Address Output High	Figures 7a, 7b		40	60				ns
t_{ASA}	Address Set-up Time to ADS	Figures 7a, 7b, 8a, 8b	15						ns
t_{AHA}	Address Hold Time from ADS	Figures 7a, 7b, 8a, 8b	15						ns
t_{ADS}	Address Strobe Pulse Width	Figures 7a, 7b, 8a, 8b	30						ns
t_{WPDL}	\overline{WIN} to \overline{WE} Output Delay	Figure 7b	15	25	30				ns
t_{WPDH}	\overline{WIN} to \overline{WE} Output Delay	Figure 7b	15	30	60				ns
t_{CRS}	\overline{CASIN} Set-up Time to \overline{RASIN} High (Mode 6)	Figure 8b	35						ns
t_{CPDL}	\overline{CASIN} to \overline{CAS} Delay ($\overline{R/C}$ low in Mode 4)	Figure 7b	32	41	58				ns
t_{CPDH}	\overline{CASIN} to \overline{CAS} Delay ($\overline{R/C}$ low in Mode 4)	Figure 7b	25	39	50				ns
t_{RCC}	Column Select to Column Address Valid	Figure 7a		40	58				ns
t_{RCR}	Row Select to Row Address Valid	Figures 7a, 7b		40	58				ns
t_{RHA}	Row Address Held from Column Select	Figure 7a	10						ns
t_{CCAS}	$\overline{R/C}$ Low to \overline{CAS} Low (Mode 4 Auto \overline{CAS})	Figure 7a		55	75				ns
t_{DIF1}	Maximum ($t_{RPDL} - t_{RHA}$)	See Mode 4 description			13				ns
t_{DIF2}	Maximum ($t_{RCC} - t_{CPDL}$)	See Mode 4 description			13				ns
Refresh Parameter									
t_{RC}	Refresh Cycle Period	Figure 2	100						ns
$t_{RASINLH}$	Pulse Width of \overline{RASIN} during Refresh	Figure 2	50						ns
t_{RFPDL}	\overline{RASIN} to \overline{RAS} Delay during Refresh	Figures 2, 9	35	50	70				ns
t_{RFPDH}	\overline{RASIN} to \overline{RAS} Delay during Refresh	Figures 2, 9	30	40	55				ns
t_{RFLCT}	\overline{RFSH} Low to Counter Address Valid	$\overline{CS} = X$, Figures 2,3,4		47	60				ns
t_{RFHRV}	\overline{RFSH} High to Row Address Valid	Figures 2, 3		45	60				ns
t_{ROHNC}	\overline{RAS} High to New Count Valid	Figures 2, 4		30	55				ns
t_{RLEOC}	\overline{RASIN} Low to End-of-Count Low	$C_L = 50\text{pF}$, Figure 2			80				ns
t_{RHEOC}	\overline{RASIN} High to End-of-Count High	$C_L = 50\text{pF}$, Figure 2			80				ns
t_{RGEOB}	\overline{RGCK} Low to End-of-Burst Low	$C_L = 50\text{pF}$, Figure 4			95				ns
t_{MCEOB}	Mode Change to End-of-Burst High	$C_L = 50\text{pF}$, Figure 4			75				ns
t_{RST}	Counter Reset Pulse Width	Figure 2	70						ns
t_{CTL}	\overline{RF} I/O Low to Counter Outputs All Low	Figure 2			100				ns

Switching Characteristics (Cont'd)

Symbol	Access Parameter	Conditions	8409 – 2						Units
			Min	Typ	Max	Min	Typ	Max	
$t_{RFCKL,H}$	Minimum Pulse Width of RFCK	Figure 9	100						ns
T	Period of \overline{RAS} Generator Clock	Figure 3	100						ns
t_{RGCKL}	Minimum Pulse Width Low of RGCK	Figure 3	35						ns
t_{RGCKH}	Minimum Pulse Width High of RGCK	Figure 3	35						ns
t_{FRQL}	RFCK Low to Forced \overline{RFRQ} Low	$C_L = 50\text{pF}$, Figure 3		20	30				ns
t_{FRQH}	RGCK Low to Forced \overline{RFRQ} High	$C_L = 50\text{pF}$, Figure 3		50	75				ns
t_{RGRL}	RGCK Low to \overline{RAS} Low	Figure 3	50	65	95				ns
t_{RGRH}	RGCK Low to \overline{RAS} High	Figure 3	40	60	85				ns
t_{RQHRF}	\overline{RFSH} Hold Time from \overline{RFSH} \overline{RQST} (RF I/O)	Figure 3	2T						ns
t_{RFRH}	\overline{RFSH} High to \overline{RAS} High (ending forced \overline{RFSH})	See Mode 1 Descrip.	55	80	110				ns
t_{RFSRG}	\overline{RFSH} Low Set-up to RGCK Low (Mode 1)	See Mode 1 Descrip.	35						ns
t_{CSCT}	\overline{CS} High to \overline{RFSH} Counter Valid	Figure 9		55	70				ns
t_{CSRL}	\overline{CS} Low to Access \overline{RASIN} Low	See Mode 5 Descrip.	10						ns
t_{ZH}	\overline{CS} Low to Address Output High from Hi-Z	Figures 9, 12 $R1 = 3.5\text{k}$, $R2 = 1.5\text{k}$		35	60				ns
t_{HZ}	\overline{CS} High to Address Output Hi-Z from High	$C_L = 15\text{pF}$, Figures 9, 12 $R2 = 1\text{k}$, $S1$ open		20	40				ns
t_{ZL}	\overline{CS} Low to Address Output Low from Hi-Z	Figures 9, 12 $R1 = 3.5\text{k}$, $R2 = 1.5\text{k}$		35	60				ns
t_{LZ}	\overline{CS} High to Address Output Hi-Z from Low	$C_L = 15\text{pF}$, Figures 9, 12 $R1 = 1\text{k}$, $S2$ open		25	50				ns
t_{HZH}	\overline{CS} Low to Control Output High from Hi-Z High	Figures 9, 12 $R2 = 750\Omega$, $S1$ open		50	80				ns
t_{HHZ}	\overline{CS} High to Control Output Hi-Z High from High	$C_L = 15\text{pF}$, Figures 9, 12 $R2 = 750\Omega$, $S1$ open		40	75				ns
t_{HZL}	\overline{CS} Low to Control Output Low from Hi-Z High	Figure 12, $S1$, $S2$ open		45	75				ns
t_{LHZ}	\overline{CS} High to Control Output Hi-Z High from Low	$C_L = 15\text{pF}$, Figure 12, $R2 = 750\Omega$, $S1$ open		50	80				ns

Input Capacitance $T_A = 25^\circ\text{C}$ (Notes 2, 6)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C_{IN}	Input Capacitance ADS, R/\overline{C}			8		pF
C_{IN}	Input Capacitance All Other Inputs			5		pF

Note 1: "Absolute Maximum Ratings" are the values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0\text{V}$.

Note 3: This test is provided as a monitor of Driver output source and sink current capability. Caution should be exercised in testing this parameter. In testing these parameters, a 15Ω resistor should be placed in series with each output under test. One output should be tested at a time and test time should not exceed 1 second.

Note 4: Input pulse 0V to 3.0V, $t_R = t_F = 2.5\text{ns}$, $f = 2.5\text{MHz}$, $t_{PW} = 200\text{ns}$. Input reference point on AC measurements is 1.5V. Output reference points are 2.7V for High and 0.8V for Low.

Note 5: The load capacitance on RF I/O should not exceed 50pF.

Note 6: Applies to all DP8409 versions unless otherwise specified.

Note 7: The DP8409-2 device can only be used with memory devices that meet the t_{RAH} specification indicated.

Applications

If external control is preferred, the DP8409 may be used in Mode 0 or 4, as in Figure 6.

If basic auto access and refresh are required, then in cases where the user requires the minimum of external complexity, Modes 1 and 5 are ideal, as shown in Figure 13a. The DP843X2 is used to provide proper arbitration between memory access and refresh. This chip supplies all the necessary control signals to the processor as well as the DP8409. Furthermore, two separate CAS outputs are also included for systems using byte-writing. The refresh clock RFCK may be divided down from either RGCK using an IC counter such as the DM74LS393 or better still, the DP84300 Programmable Refresh Timer. The DP84300 can provide RFCK periods ranging from 15.4µs to 15.6µs based on the input clock of 2 to 10MHz. Figure 13b shows the general timing diagram for interfacing the DP8409 to different microprocessors using the interface controller DP843X2.

If the system is complex, requiring automatic access and refresh, burst refresh, and all-banks auto-write, then more circuitry is required to select the mode. This may be accomplished by utilizing a PAL. The PAL has two functions. One as an address comparator, so that when the desired port address occurs (programmed in the PAL), the comparator gates the data into a latch, where it is connected to the mode pins of the DP8409. Hence the mode of the DP8409 can be changed as desired with one PAL chip merely by addressing the PAL location, and then outputting data to the mode-control pins. In this manner, all the automatic modes may be selected, assigning R/C as RFCK always, and CASIN as RGCK always. The output from RF I/O may be used as End-of-Count to an interrupt, or Refresh Request to HOLD or BUS REQUEST. A complex system may use Modes 5 and 1 for automatic access and refresh, Modes 3a and 7 for system initialization, and Mode 2 (auto-burst refresh) before and after DMA.

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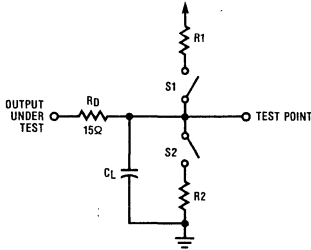


FIGURE 11. Output Load Circuit

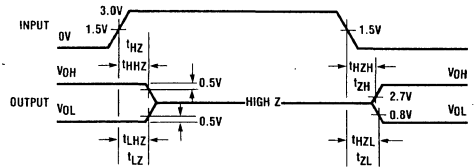


FIGURE 12. Waveform

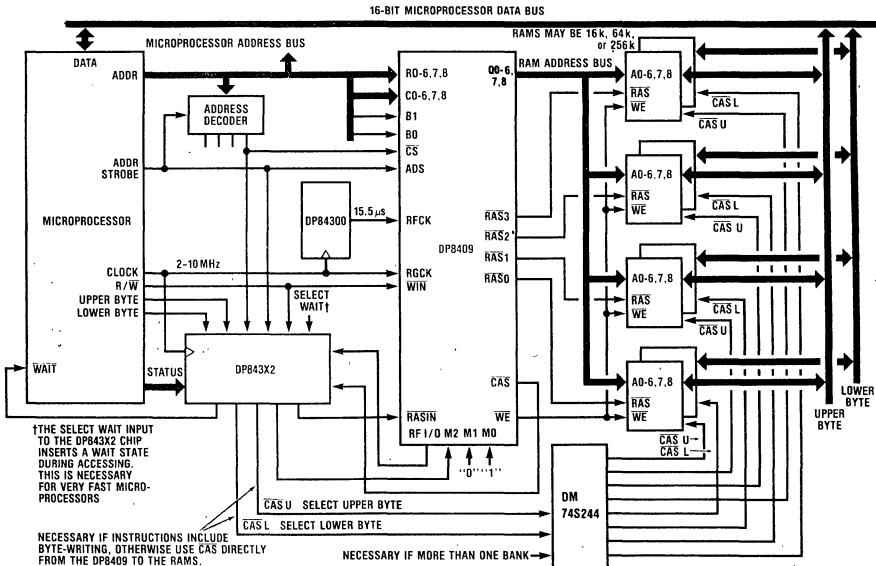


FIGURE 13a. Connecting the DP8409 Between the 16-bit Microprocessor and Memory

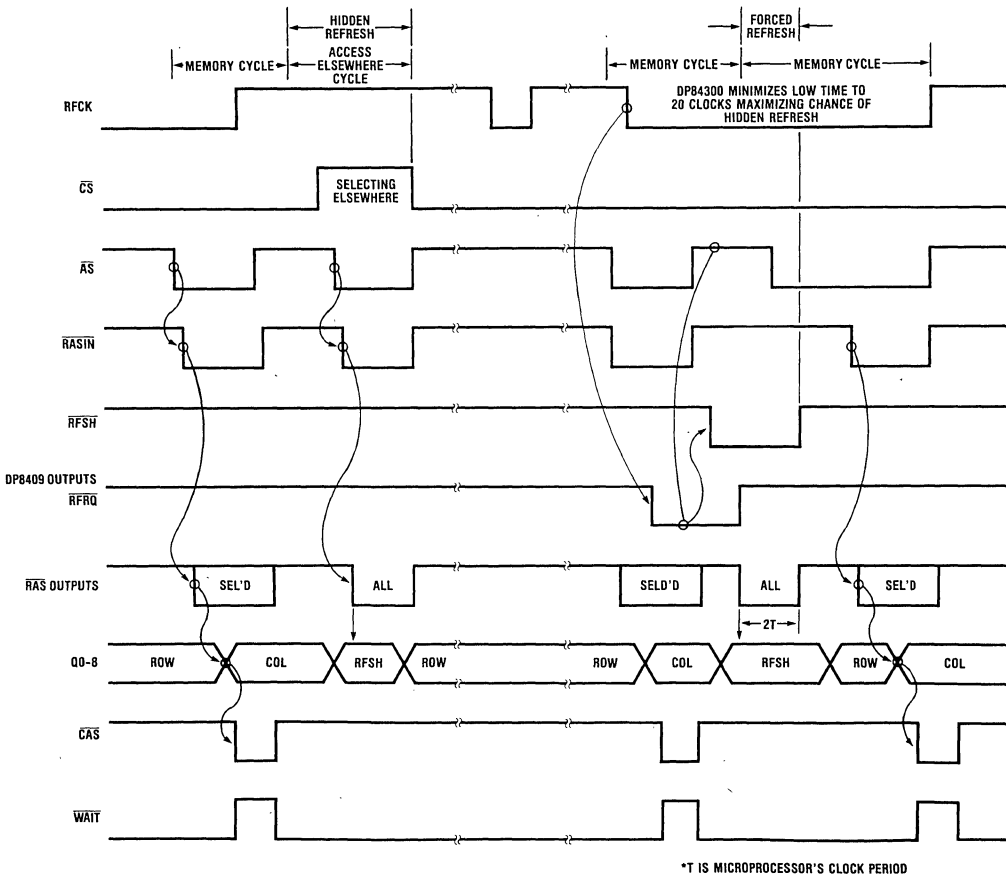


FIGURE 13b. DP8409 Auto Refresh

DP8419 High Speed Dynamic RAM Controller/Driver

General Description

The DP8419 High Speed DRAM Controller/Driver combines the most popular memory control features of the DP8408/9 DRAM Controller/Driver with the high speed of Bipolar Oxide Isolation processing.

The DP8419 retains the high capacitive-load drive capability of the DP8408/9 as well as its most frequently used access and refresh modes, allowing it to directly replace the DP8408/9 in applications using only modes 0, 1, 4 and 5. Thus, the DP8419 will allow most DP8408/9 users to directly upgrade their system simply by replacing their old controller chip with the DP8419.

Since only two of the three mode pins from the DP8408/9 are necessary to select the four available DP8419 modes, M1 of the DP8408/9 is called RAHS on the DP8419 and allows the user the option of selecting t_{RAH} to suit his DRAMs.

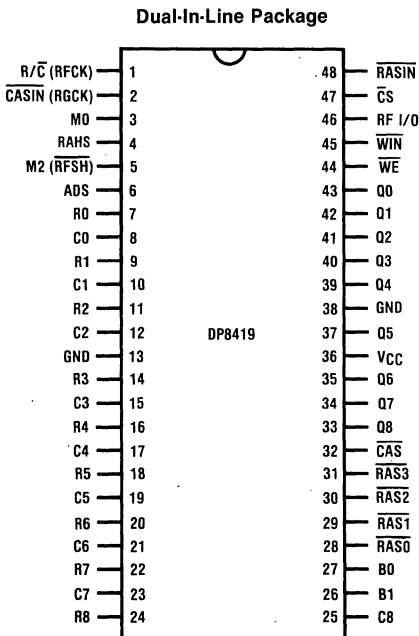
Figure 1 shows the DP8419 pinout. It is identical to that of the DP8408/9, except for pin 4 which has become RAHS.

Table 1 is a DP8419 mode table. Pins 3 and 5 are used to select from the four available operational modes. Note that the mode selection scheme is identical to that of the DP8408/9 with M1 (pin 4) tied low.

Features

- Pin and functionally compatible with the DP8408/9 DRAM Controllers in most applications
- Significantly faster memory access and refresh due to Bipolar Oxide Isolation processing
- Choice of t_{RAH} is pin selectable
- Nibble mode accessing available in external control mode

Connection Diagram



TOP VIEW
FIGURE 1.

Table 1. DP8419 Mode Select Options

Mode	(RFSH) M2	M0	Mode of Operation
0	0	0	Externally Controlled Refresh
1	0	1	Auto Refresh — Forced
4	1	0	Externally Controlled Access
5	1	1	Auto Access (Hidden Refresh)

DP8408, DP8409

Application Hints

National Semiconductor
Application Brief #1
Tim Garverick
June 1983



The DP8408, DP8409 dynamic RAM controllers have been well received by dynamic memory users because they perform functions formerly requiring multiple integrated circuit chips. These controllers are designed to be suitable for a variety of DRAM control methods. As a result of the many combinations of ways in which inputs to these chips may be varied, it was inevitable that certain conditions exist that would cause the DP8408, DP8409 to respond in an undesirable way. Feedback from customers using these chips has resulted in thorough investigations of such conditions. The following are constraints on the use of the DRAM controllers which are not addressed in their data sheets. The majority of customers will find that most of the items on this list are not pertinent to their particular application, and those that are impose minimal restrictions.

- 1) The on-chip refresh counter resets when the RFI/O pin goes low for a refresh request in mode 5 if this pin is excessively loaded with capacitance. The data sheet suggests that this pin not be loaded with greater than 50 pF. Since RFI/O, in most cases, needs only to drive a low capacitance in a refresh control circuit, this limit is not unreasonable.
- 2) When the DP8408, DP8409 is in a refresh mode, the RFI/O pin indicates that the on-chip refresh counter has reached its end-of-count. This end-of-count is selectable as 127, 255 or 511 (511 is available only on the DP8409) to accommodate 16k, 64k or 256k DRAMs, respectively. Although the end-of-count may be chosen to be any of these, the counter always counts to 511 (255 for the DP8408) before rolling over to zero.
- 3) In mode 5, the DP8409 requests a refresh when RFI/O goes low following RFCK (R/C). DP8409s with date code 8209 or earlier, have a slight functional difference from later DP8409s. With $\overline{CS} = 1$, RFI/O goes low for only about 10 ns when RFCK goes low, for early DP8409s. It stays high until mode 1 is entered and then responds as specified in the data sheet. DP8409s with date codes after 8209 function as shown in the data sheet with $\overline{CS} = 1$. If $\overline{CS} = 0$ all DP8409s operate as specified in the data sheet.
- 4) When going from mode 0, 1 or 2 (refresh) to mode 5 of the DP8408, if \overline{CASIN} and R/C are both low, a glitch occurs on the \overline{CAS} output. Since neither of these inputs is used in these modes, one or both should be held high.
- 5) Most DRAMs specify 0 ns row address set-up time to \overline{RAS} . In order to guarantee this, the row address to the DP8408, DP8409 must be valid 10 ns before \overline{RASIN} transitions low to initiate an access. In terms of the data sheet parameters, maximum $(t_{APD} - t_{RPDL}) = 10$ ns.
- 6) When changing modes from refresh to access, again sufficient time must be allowed for the row address to be valid before \overline{RAS} occurs. In this case, the address outputs of the DP8408, DP8409 are changing from the refresh counter to the row address inputs. In order for the row address to be set up a minimum of 0 ns before \overline{RAS} goes low, \overline{RASIN} should not go low until 30 ns after the change from refresh to access mode.
- 7) Both the low and high pulse widths of \overline{RAS} have minimum requirements during refresh. When in mode 0, the \overline{RASIN} to \overline{RAS} low delay is longer than the \overline{RASIN} to \overline{RAS} high delay. In terms of the data sheet parameters, maximum $(t_{RFPDL} - t_{RFPDH}) = 25$ ns. Thus, the minimum low pulse width of \overline{RAS} in mode 0 equals the \overline{RASIN} low pulse width minus 25 ns. The minimum high pulse width of \overline{RAS} in mode 0 equals the \overline{RASIN} high pulse width.
- 8) The fastest memory access may be accomplished using mode 4 and external delay lines (see App. Brief #9).
- 9) In the data sheet, it is specified that \overline{CS} should go low 15 ns (t_{CSLR}) before \overline{RASIN} goes low to initiate an access in mode 5. This is to prevent the possibility of a glitch on the \overline{RAS} outputs, resulting from the DP8409 interpreting the \overline{RASIN} as a hidden refresh. For the same reason, \overline{CS} should be held low for a minimum of 15 ns after \overline{RASIN} returns high, ending the access in mode 5.
- 10) If the DP8409 is being used in mode 5 and $\overline{CS} = 1$, and if \overline{RASIN} goes low within 15 ns before RFCK (R/C) goes low, up to a 15 ns glitch may occur on the refresh request pin, RFI/O. However, since \overline{CS} is high, a hidden refresh will occur as it normally would with RFCK high. If the glitch on RFI/O were detected and interpreted as a forced refresh request, no forced refresh would be allowed by the DP8409 since a hidden refresh was allowed. This would not cause any problem, however, since the hidden refresh has taken care of the refresh requirement for that period of RFCK. Also, this forced refresh request could not be detected if the system does not check RFI/O for a low state while \overline{RASIN} is low (i.e., an access is taking place).

DP8408/9

Fastest DRAM Access Mode

National Semiconductor
Application Brief # 9
Tim Garverick
Rusty Meier
February 1983



If one desires the fastest possible operation of the DP8408/9 multi-mode dynamic RAM controller/driver in accessing DRAMs, mode 4, externally controlled access mode should be considered.

In using mode 4 there are three input signals which must be considered:

- 1) $\overline{\text{RASIN}}$ — generates $\overline{\text{RAS}}$
- 2) R/C — switches between rows and columns on the address outputs
- 3) $\overline{\text{CASIN}}$ — generates $\overline{\text{CAS}}$

In producing these signals a delay will be needed between $\overline{\text{RASIN}}$ and R/C and between R/C and $\overline{\text{CASIN}}$. (Note: In mode 4 external generation of $\overline{\text{CASIN}}$ can produce $\overline{\text{CAS}}$ faster than automatic generation of $\overline{\text{CAS}}$.)

Two important parameters have been added to the DP8408/9 data sheets that help one compute the minimum acceptable delays between the above-mentioned signals. These parameters are:

- 1) $t_{\text{DIF1}} = \text{MAXIMUM} (t_{\text{RPDL}} - t_{\text{RHA}}) = 13 \text{ ns}$
 where $t_{\text{RPDL}} = \overline{\text{RASIN}}$ to $\overline{\text{RAS}}$ delay
 $t_{\text{RHA}} = \text{row address held from column select}$
- 2) $t_{\text{DIF2}} = \text{MAXIMUM} (t_{\text{RCC}} - t_{\text{CPDL}}) = 13 \text{ ns}$
 where $t_{\text{RCC}} = \text{column select to column address valid}$
 $t_{\text{CPDL}} = \overline{\text{CASIN}}$ to $\overline{\text{CAS}}$ delay

These parameters are specified as being less than what would be calculated using the min/max values given for t_{RCC} , t_{CPDL} , t_{RPDL} and t_{RHA} in the DP8408/9 specification sheets, because on-chip delays track over temperature and supply variations.

The equation for the delay between $\overline{\text{RASIN}}$ and R/C that guarantees the specified DRAM t_{RAH} is:

$$\begin{aligned} \text{min delay required} &= t_{\text{DIF1}} + t_{\text{RAH}} \\ &= 13 \text{ ns} + t_{\text{RAH}} \end{aligned}$$

where $t_{\text{RAH}} = \text{DRAM minimum row address hold time from } \overline{\text{RAS}}$

The equation for the delay between R/C and $\overline{\text{CASIN}}$ that guarantees the specified DRAM t_{ASC} is:

$$\begin{aligned} \text{min delay required} &= t_{\text{DIF2}} + t_{\text{ASC}} \\ &= 13 \text{ ns} + t_{\text{ASC}} \end{aligned}$$

where $t_{\text{ASC}} = \text{DRAM minimum column address set-up time to } \overline{\text{CAS}}$

To produce the above-mentioned delays between signals, a $\pm 2 \text{ ns}$ resolution delay line can be used as follows:

$$\begin{aligned} (\text{assuming } t_{\text{RAH}} = 20 \text{ ns, } t_{\text{ASC}} = 0 \text{ ns}) \\ \overline{\text{RASIN}} \text{ to } \text{R/C} \text{ delay} &= 13 \text{ ns} + 20 \text{ ns} \\ &= 33 \text{ ns} \\ \text{R/C} \text{ to } \overline{\text{CASIN}} \text{ delay} &= 13 \text{ ns} + 0 \text{ ns} \\ &= 13 \text{ ns} \end{aligned}$$

Thus, R/C must follow $\overline{\text{RASIN}}$ by a minimum of 33 ns and $\overline{\text{CASIN}}$ must follow R/C by a minimum of 13 ns. With a delay line of $\pm 2 \text{ ns}$ resolution, the $\overline{\text{RASIN}}$ to R/C and R/C to $\overline{\text{CASIN}}$ delays can be typical of 35 ns and 15 ns, respectively. (See *Figures 1 and 2* below.)

This scheme will provide a maximum $\overline{\text{RASIN}}$ to $\overline{\text{CAS}}$ delay of:

$$\begin{aligned} 35 \text{ ns} + 15 \text{ ns} + 2 \text{ ns} (\text{resolution uncertainty}) \\ + \text{MAXIMUM} (t_{\text{CPDL}}) = 52 \text{ ns} + \text{MAXIMUM} (t_{\text{CPDL}}) \end{aligned}$$

For the DP8408/9-2, $\text{MAXIMUM} (t_{\text{CPDL}}) = 58 \text{ ns}$.

For the DP8408/9 (no dash), $\text{MAXIMUM} (t_{\text{CPDL}}) = 68 \text{ ns}$ (not 58 ns as indicated in data sheets up to November 1982).

The fastest mode 4 accesses (with the assumed delay line and DRAM parameters) are therefore, 110 ns and 120 ns, respectively, for the -2 and non-dash parts.

The maximum $\overline{\text{RASIN}}$ to $\overline{\text{CAS}}$ delay (t_{R1CL}) in mode 5 (auto mode) for the DP8408/9-2 (which guarantees a min t_{RAH} of 20 ns) is 130 ns. The maximum t_{R1CL} in mode 5 for the DP8408/9 (no dash) is 160 ns.

Thus, it is shown that if the features offered by the DP8408/9 automatic modes can be sacrificed, mode 4 (externally controlled access) may be used to obtain the fastest memory access.

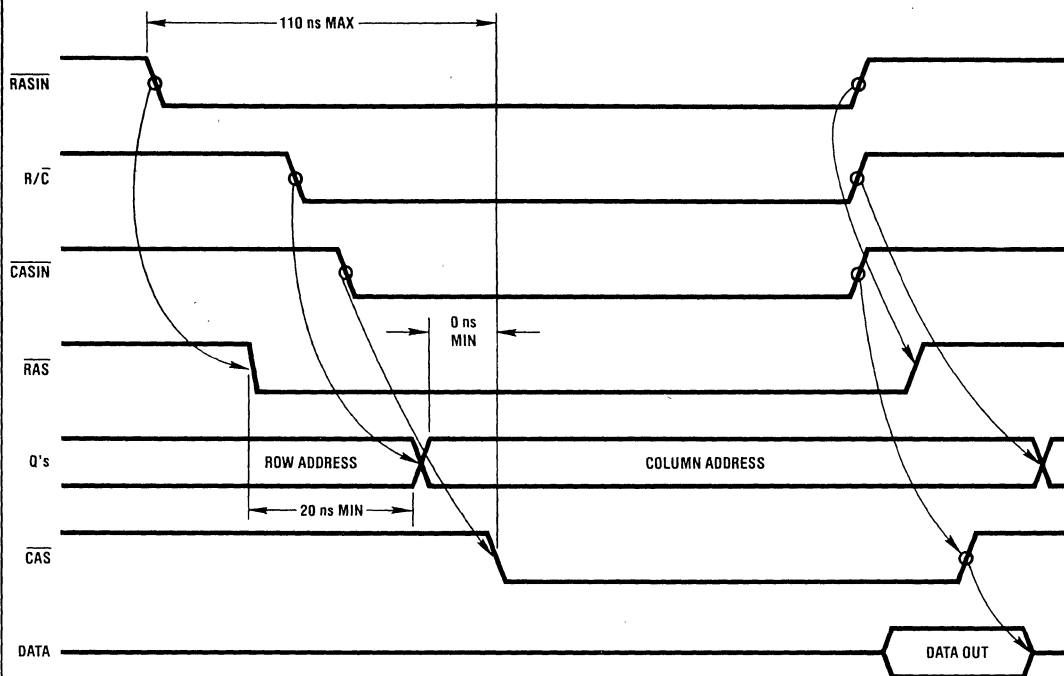


Figure 1. Mode 4 Timing Relationships

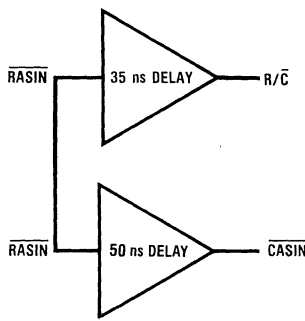


Figure 2. Mode 4 Externally Generated Signals

Precautions to Take When Driving Memories

National Semiconductor
Application Note AN-305
June 1982
Mike Evans



As memory prices continue their relentless reduction of cost per bit, more and more systems designers are incorporating memories into their designs. In general these memories comprise a number of dynamic RAMs, such as the 64k x 1. In this x1 configuration, the number of RAMs required is a multiple of the bus width. Most new system designs use 16-bit microprocessors, so that a typical memory will comprise from 16 to 64 DRAMs, thus providing from 64k to 256k addressing capability. This means the memory drivers have to drive upwards of 16 RAMs. The drivers may be part of an integrated circuit dynamic RAM controller such as the DP8408/DP8409, or they may be on a separate chip such as the DP84240/DP84244 octal memory drivers. The recommendations in this article are valid for any type of memory driver. The purpose of the article is to forewarn new designers using memories of problems they will encounter if adequate precautions are not taken.

A typical configuration of a 16-bit wide memory is shown in *Figure 1*. Each driver address output goes to every dynamic RAM, as does \overline{WE} . \overline{CAS} outputs go to half the number of RAMs assuming byte writing is required. \overline{RAS} outputs each go only to one bank. Note that these loads are not true for the data inputs and outputs. Each data I/O only connects to its respective bit, so the loading is only one RAM per bank for data. In general, this is why buffers are not required on the data bus when interfacing to memory. Data In of the RAMs can be linked directly to Data Out for any one bit, and also to the corresponding bit on the data bus. This is true for normal read and write operations, but if read-modify-write cycles are employed, the Data Out signals must be buffered from the data bus.

Using this typical memory configuration may not be as simple as it seems. Without care and attention, problems can arise for the unprepared, and there are two areas in particular which may cause memory errors or memory damage: one is voltage overshoot caused by inductive traces and high capacitive loads, the other is switching spikes caused by switching high capacitive loads.

Overshoot and Undershoot (Undershoot is Negative Overshoot)

When a system requires a number of dynamic RAMs, the result is high capacitance loads, caused by a combination of RAM input capacitance and trace capacitance. Each dynamic RAM has a specified input capacitance of 10pF maximum, but most dynamic RAMs are closer to 2 to 3pF. Very few actually get close to 10pF, even under worst case conditions of high temperature and V_{CC} . It is safe, therefore, to assume a much lower average input capacitance when using 16 or more RAMs.

In fact, the input capacitance of most inputs is due more to the package than the input gating, because the silicon gate inputs of the transistors in today's market have such high impedance. A typical maximum would be 2.5pF. Control inputs such as \overline{RAS} and \overline{CAS} connect to more than one transistor input. For example, on the National Semiconductor 64k x 1 dynamic RAM, the NMC4164, \overline{RAS} goes to two transistors and \overline{CAS} to four. In general, this is true for most manufacturers' RAMs, so a more typical maximum input capacitance would be 3pF for \overline{RAS} and 3.5pF for \overline{CAS} . RAM input currents are so small as to be negligible. The input current is quoted as 10 μ A maximum, but again most RAMs are much less than this in a typical memory. Driving DRAMs, therefore, is not a problem of DC drive capability, but rather a problem of capacitance drive capability.

Driving DRAM input capacitance is further compounded by printed circuit traces, and even more so by wire-wrapping. Both can be represented by a transmission line with distributed capacitance and inductance. Thus, the total load is equivalent to a complex impedance comprising the distributed trace inductance, and a capacitance comprising distributed trace capacitance and RAM input capacitance as shown in *Figure 2a*.

The effect is an overshoot or undershoot at the dynamic RAM inputs that occurs each time a memory driver changes state, as shown in *Figure 2b*. As the driver output changes state, the load capacitance cannot be instantaneously charged or discharged because the current available is limited both by the driver transistor impedance, and the equivalent series resistance from the supply rail through the chip to the trace resistance. This current will be similar in value to the quoted short circuit current of the driver stage; therefore, there is a spike of current that lasts as long as it takes to change the voltage of all the capacitances. For the driver stages of the DP8408/DP8409, or the DP84240/DP84244, the typical short circuit current is 100mA per stage. This is true for either direction, so that the high-to-low transition takes roughly the same time as the low-to-high transition, minimizing skew times on all the driver outputs, as they transition in either direction. Assuming the output low voltage, V_{OL} , is 0.2V and the output high voltage, V_{OH} , is 3.2V, and that the charge/discharge current is constant at I_{SC} , then the current spike will exist for a time, T,

$$T = C_L \times (V_{OH} - V_{OL}) / I_{SC}$$

$$= 500 \text{ pF} \times 3.0 \text{ V} / 100 \text{ mA} = 15 \text{ ns}$$

C_L (500pF) is the load capacitance of typically 64 to 88 dynamic RAMs, in other words, four banks comprising 16 data bits and possibly six check bits if error correction is required.

In fact, due to the trace inductance, the rate of change of current will not be a step function, so that the current waveform looks like a spike. Even so, the rapid rate of change of current, di/dt , into the trace inductance L , will create a potentially excessive voltage "e" across this inductance. As an example, if the current changes from 0 to 100mA in 6ns, and the composite trace inductance is $0.3\mu\text{H}$, then the voltage across this inductance is "e," where,

$$e = L di/dt \\ = 0.3\mu\text{H} \times 100\text{mA}/6\text{ns} = 5\text{V}$$

In other words, at this rate of change in current, even a small inductance can be dangerous for two reasons. First, the dynamic RAMs at the far end of the trace could be destroyed, unless they have clamping diodes to V_{CC} and GND (most do not), or second, the returning voltage may exceed the threshold it has just passed causing a second and then third change of state. If this sudden glitch occurs on a control signal input such as RAS, the memory contents may be inadvertently changed.

It is therefore necessary to remove the spike. The most common approach is to insert a damping resistor in the path between the driver and the RAMs, fairly close to the

driver, as shown by R_D in Figure 2a. The best value for the resistor is the critical value giving a critically damped transition. Too high a value will cause overdamping which results in a slow transition. This slow edge may create excessive skew problems and slow down the memory cycle, or even worse, the edge may be slow enough that the RAM cycle never begins internally. If the damping resistor value is too low, the undershoot or overshoot may not be removed. It is therefore recommended that the resistor be determined on the first prototypes (not wire-wrapped prototypes because the value will be different due to the larger distributed inductance and capacitance). Also, the values may be different for the control lines, particularly CAS. If there are a number of banks, and a RAS is used to select each bank, then the damping resistor in this line will be higher.

Typical values for the damping resistors will be between 15Ω and 100Ω , the lower the loading, the higher the values. Some IC manufacturers offer octal memory drivers with on-chip series resistors fixed at $\approx 25\Omega$. Unless this is the critical value required for all the lines, problems will arise. The DP8400 family has been designed with equivalent internal values of approximately 10Ω , allowing for any external value of damping resistor.

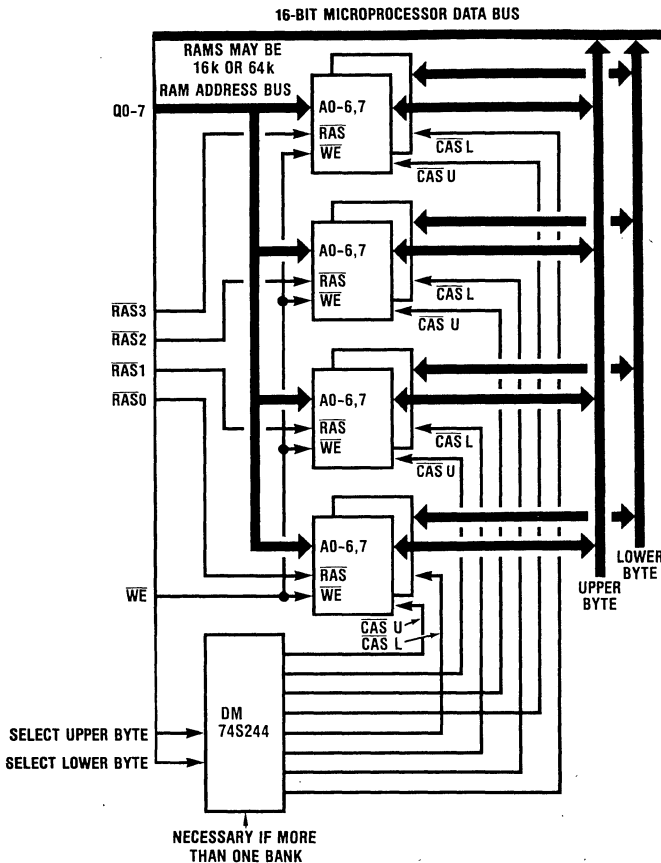


Figure 1. Typical 16-Bit Memory with Byte Write Address

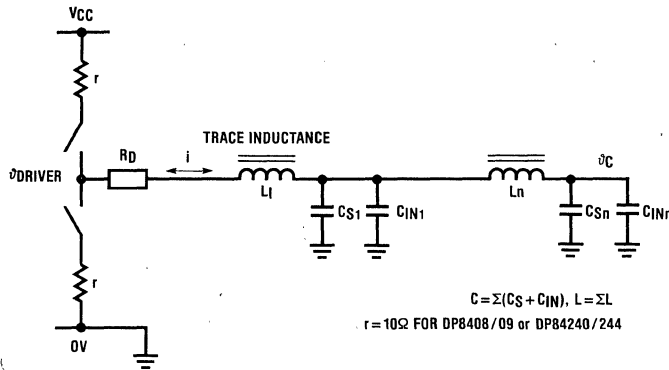


Figure 2a. Complex Load Impedance Caused by Distributed Trace Inductance L and Capacitance C_S , and RAM Input Capacitance C_{IN}

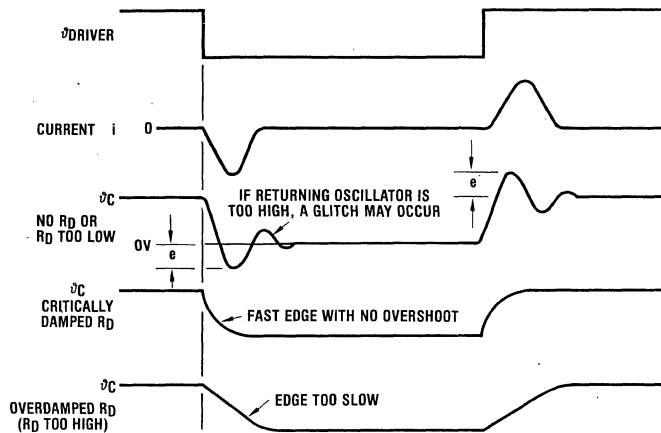


Figure 2b. Timing Waveforms Showing the Effect of Variations of R_D on Signals Appearing at the RAM

Switching Current Spikes

Another major undesirable effect of the fast current spikes is the effect on the V_{CC} and GND pins. The worst case is when all eight or nine address outputs switch in the same direction at the same time, as shown in Figure 3a. If each driver can source or sink 100mA, then a current of approximately 1A could enter or exit the driver chip in a period of 20ns. The resistance and inductance of the V_{CC} and GND lines to the chip can cause excessive drops during this switching time (see waveforms in Figure 3a), which may, in turn, upset latches either in the DP8408/DP8409, or externally. A ceramic capacitor connected across V_{CC} and GND pins will largely remove the spike. A $1\mu\text{F}$ multilayer ceramic is recommended. This should be fitted as close as possi-

ble to the pins in order to reduce lead inductance. The DP8408/DP8409 pin configuration facilitates this with GND and V_{CC} pins 0.2" apart so that the ceramic capacitor can be fitted as close to the chip as possible. The second GND pin should also be decoupled. These GND and V_{CC} pins are located in the center of the package to reduce bonding lead lengths. In fact, the lead resistance is five times lower than if the supply pins were in the corners. An example of how this spike can be reduced would be the previous example of a 1A change in supply current switching in 20ns with a $1\mu\text{F}$ ceramic capacitor decoupling GND and V_{CC} . The voltage drop " v " is $1\text{A} \times 20\text{ns} / 1\mu\text{F}$, or 20mV.

If the decoupling capacitor was $0.01\ \mu\text{F}$, the drop would be 2V. Tantalum or other types of capacitors are lower frequency capacitors and have only a small effect in reducing the voltage spike. Ceramic capacitors are high frequency, and multilayer capacitors with lower inductance have a greater effect in reducing the voltage spike and are therefore recommended. As a further recommendation, the dynamic RAMs should be similarly decoupled with approximately a $0.1\ \mu\text{F}$ ceramic capacitor on each RAM. Wire-wrapped boards, in particular, need special attention.

There are some other precautions that may be considered when driving memories. First, be aware that IC

sockets increase load capacitance and inductance, so it becomes a matter of the importance of removability of chips, and maintainability. Also, shorter, thicker trace lengths will reduce the load, and good GND and V_{CC} connections will help reduce the voltage spikes around the memory board. For wire-wrapped designs, GND and V_{CC} should be multiwired.

With proper decoupling and correct selection of damping resistors, integrated circuit dynamic RAM controllers will function as expected to ease the burden of the system designer.

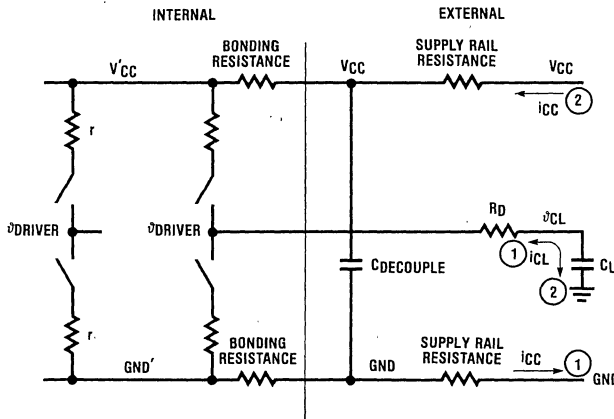


Figure 3a. Effect of Switching All Outputs Simultaneously in the Same Direction

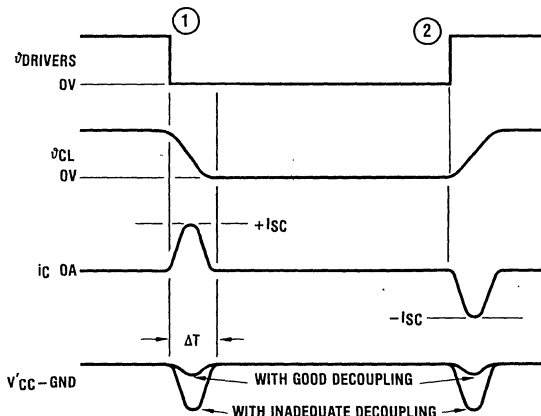
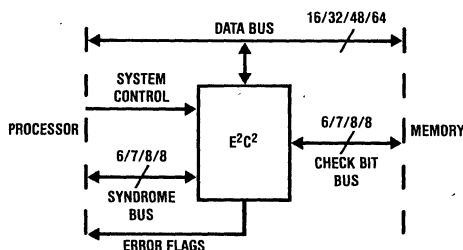


Figure 3b. Timing Waveforms Showing Internal Supply Rail Drops During Output Switching

DP8400 — E²C² Expandable Error Checker and Corrector

General Description

The DP8400 Expandable Error Checker and Corrector (E²C²) aids system reliability and integrity by detecting errors in memory data and correcting single or double-bit errors. The E²C² data I/O port sits across the processor-memory data bus as shown, and the check bit I/O port connects to the memory check bits. Error flags are provided, and a syndrome I/O port is available. Fabricated using high speed Schottky technology in a 48-pin dual-in-line package, the DP8400 has been designed such that its internal delay times are minimal, maintaining maximum memory performance.



For a 16-bit word, the DP8400 monitors data between the processor and memory, with its 16-bit bidirectional data bus connected to the memory data bus. The DP8400 uses an encoding matrix to generate 6 check bits from the 16 bits of data. In a WRITE cycle, the data word and the corresponding check bits are written into memory. When the same location of memory is subsequently read, the E²C² generates 6 new check bits from the memory data and compares them with the 6 check bits read from memory to create 6 syndrome bits. If there is a difference (causing some syndrome bits to go high), then that memory location contains an error and the DP8400 indicates the type of error with 3 error flags. If the error is a single-bit error, the DP8400 will automatically correct it.

The DP8400 is easily expandable to other data configurations. For a 32-bit data bus with 7 check bits, two DP8400s can be used in cascade with no other ICs. Three DP8400s can be used for 48 bits, and four DP8400s for 64 data bits, both with 8 check bits. In all these configurations, single and double-error detection and single-error correction are easy to implement.

When the memory is more unreliable, or better system integrity is preferred, then in any of these configurations, double-error correction can be performed. One approach requires a further memory WRITE-READ cycle using complemented data and check bits from the DP8400. If at least one of the two errors is a hard error, the DP8400 will correct both errors. This implementation requires no more memory check bits or DP8400s than the single-error correct configurations.

The DP8400 has a separate syndrome I/O bus which can be used for error logging or error management. In addition, the DP8400 can be used in BYTE-WRITE applications (for up to 72 data bits) because it has separate byte controls for the data buffers. In 16 or 32-bit systems, the DP8400 will generate and check system byte parity, if required, for integrity of the data supplied from or to the processor. There are three latch controls to enable latching of data in various modes and configurations.

Operational Features

- Fast single and double-error detection
- Fast single-error correction
- Double-error correction after catastrophic failure with no additional ICs or check bits
- Functionally expandable to 100% double-error correct capability
- Functionally expandable to triple-error detect
- Directly expandable to 32 bits using 2 DP8400s only
- Directly expandable to 48 bits using 3 DP8400s only
- Directly expandable to 64 bits using 4 DP8400s only
- Expandable to and beyond 64 bits in fast configuration with extra ICs
- 3 error flags for complete error recording
- 3 latch enable inputs for versatile control
- Byte parity generating and checking
- Separate byte controls for outputting data in BYTE-WRITE operation
- Separate syndrome I/O port accessible for error logging and management
- On-chip input and output latches for data bus, check bit bus and syndrome bus
- Diagnostic capability for simulating check bits
- Memory check bit bus, syndrome bus, error flags and internally generated syndromes available on the data bus
- Self-test of E²C² on the memory card under processor control
- Full diagnostic check of memory with the E²C²
- Complete memory failure detectable
- Power-on clears data and syndrome input latches

Timing Features

16-BIT CONFIGURATION

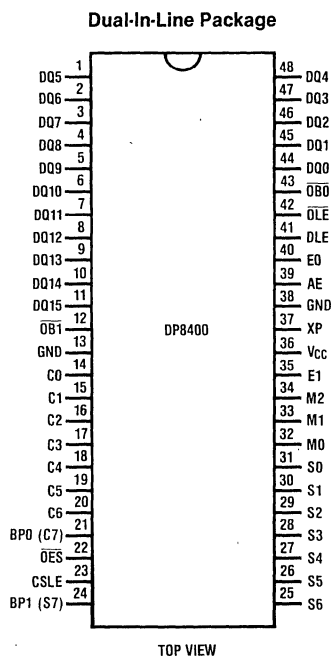
- WRITE Time: 35 ns from data-in to check bits valid
- DETECT Time: 35 ns from data-in to Any Error (AE) flag set
- CORRECT Time: 70 ns from data-in to correct data out

Timing Features (Continued)

32-BIT CONFIGURATION

WRITE Time: 65 ns from data-in to check bits valid
 DETECT Time: 60 ns from data-in to Any Error (AE) flag set
 CORRECT Time: 125 ns from data-in to correct data out

DP8400 Connection Diagram



Order Number DP8400N-4 or DP8400D-4
 See NS Package N48A or D48A

Pin Definitions See Figure 1 for abbreviations

V_{CC}, GND, GND: 5.0V ± 5%. The 3 supply pins have been assigned to the center of the package to reduce voltage drops, both DC and AC. Also there are two ground pins to reduce the low-level noise. The second ground pin is located two pins from V_{CC}, so that decoupling capacitors can be inserted directly next to these pins. It is important to adequately decouple this device, due to the high switching currents that will occur when all 16 data bits change in the same direction simultaneously. A recommended solution would be a 1 μF multilayer ceramic capacitor in parallel with a low-voltage tantalum capacitor, both connected close to pins 36 and 38 to reduce lead inductance.

DQ0-DQ15: Data I/O port. 16-bit bidirectional data bus which is connected to the input of DIL0 and DIL1 and the output of DOB0 and DOB1, with DQ8-DQ15 also to CIL.

C0-C6: Check-bit I/O port. 7-bit bidirectional bus which is connected to the input of the CIL and the output of the COB. COB is enabled whenever M2 is low.

S0-S6: Syndrome I/O port. 7-bit bidirectional bus which is connected to the input of the SIL and the output of the SOB.

DLE: Input data latch enable. When high, DIL0 and DIL1 outputs follow the input data bus. When low, DIL0 and DIL1 latch the input data.

CSLE: Input check bit and syndrome latch enable. When high, CIL and SIL follow the input check and syndrome bits. When low, CIL and SIL latch the input check and syndrome bits. If OES is low, SIL remains latched.

OLE: Output latch enable. OLE enables the internally generated data to DOL0, and DOL1, COL and SOL when low, and latches when high.

XP: Multi-expansion, which feeds into a three-level comparator. With XP at 0V, only 6 or 7 check bits are available for expansion up to 40 bits, allowing byte parity capability. With XP open or at V_{CC}, expansion beyond 40 bits is possible, but byte parity capability is no longer available. When XP is at V_{CC}, CG6 and CG7, the internally generated upper two check bits, are set low. When XP is open, CG6 and CG7 are set to word parity.

BP0 (C7): When XP is at 0V, this pin is byte-0 parity I/O. In the Normal WRITE mode, BP0 receives system byte-0 parity, and in the Normal READ mode outputs system byte-0 parity. When XP is open or at V_{CC}, this pin becomes C7 I/O, the eighth check bit for the memory check bits, for 48-bit expansion and beyond.

BP1 (S7): When XP is at 0V, this pin is byte-1 parity I/O. In the Normal WRITE mode, BP1 receives system byte-1 parity, and in the Normal READ mode outputs system byte-1 parity. When XP is open or at V_{CC}, this pin becomes S7 I/O, the eighth syndrome bit for 48-bit expansion and beyond.

AE: Any error. In the Normal READ mode, when low, AE indicates no error and when high, indicates that an error has occurred. In any WRITE mode, AE is permanently low.

E0: In the Normal READ mode, E0 is high for a single-data error, and low for other conditions. In the Normal WRITE mode, E0 becomes PE0 and is low if a parity error exists in byte-0 as transmitted from the processor.

E1: In the Normal READ mode, E1 is high for a single-data error or a single check bit error, and low for no error and double-error. In the Normal WRITE mode, E1 becomes PE1 and is low if a parity error exists in byte-1 as transmitted from the processor.

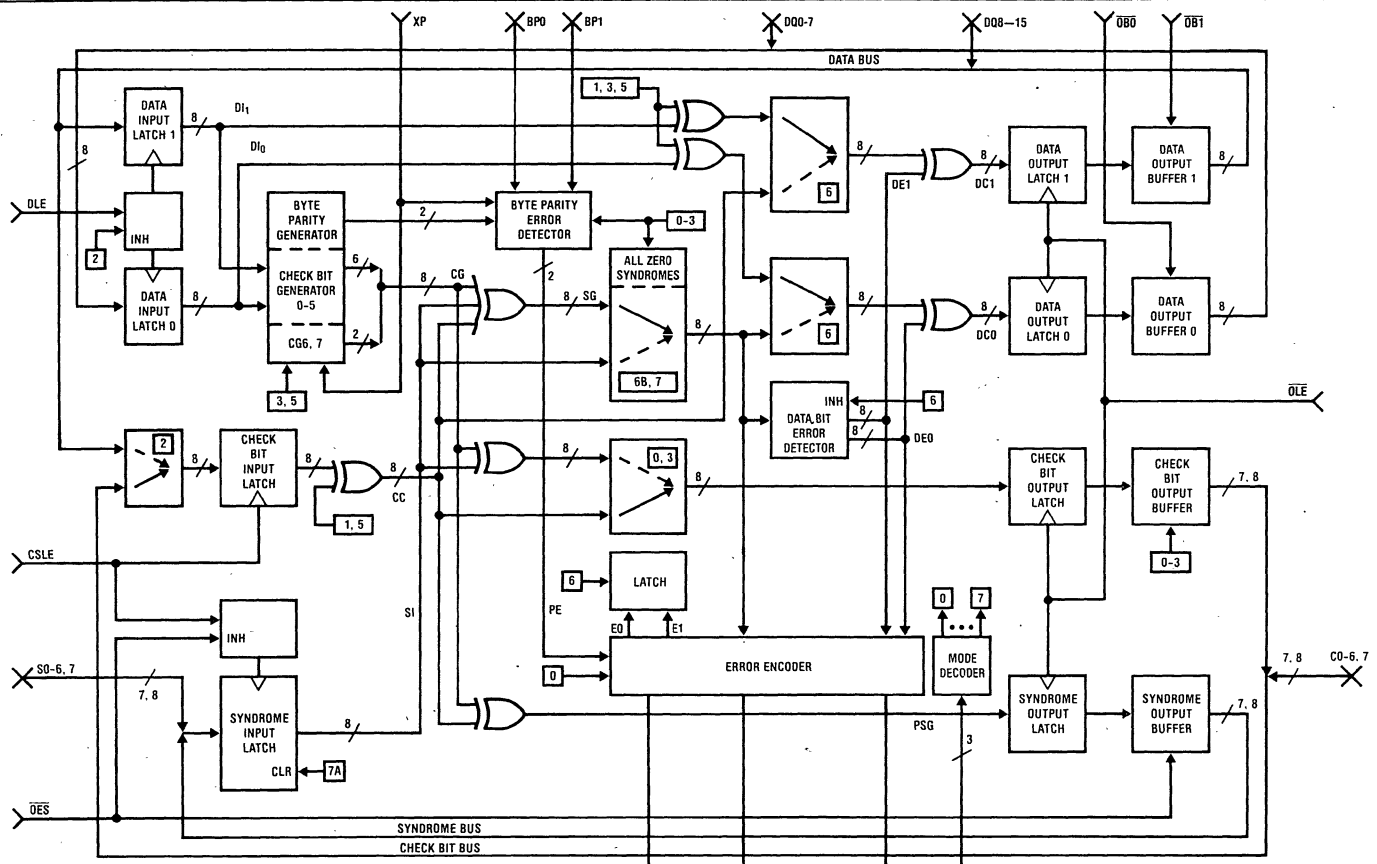
OB0, OB1: Output byte-0 and output byte-1 enables. These inputs, when low, enable DOL0 and DOL1 through DOB0 and DOB1 onto the data bus pins DQ0-DQ7 and DQ8-DQ15. When OB0 and OB1 are high the DOB0, DOB1 outputs are TRI-STATE®.

OES: Output enable syndromes. I/O control of the syndrome latches. When high, SOB is TRI-STATED and external syndromes pass through the syndrome input latch with CSLE high. When OES is low, SOB is enabled and the generated syndromes appear on the syndrome bus, also CSLE is inhibited internally to SIL.

M0, M1, M2: Mode control inputs. These three controls define the eight major operational modes of the DP8400. Table III depicts the modes.

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[n] mode of operation signifies active signal

- | | | | |
|--------|----------------------------|---------|-------------------------------|
| DIL | Data Input Latch | DOLO, 1 | Data Output Latch Bytes 0, 1 |
| CG | Check Bit Generator | COL | Check Bit Output Latch |
| CIL | Check Bit Input Latch | SOL | Syndrome Output Latch |
| CC | Check Bit Complementor | DOBO, 1 | Data Output Buffer Bytes 0, 1 |
| SIL | Syndrome Input Latch | COB | Check Bit Output Buffer |
| PSG | Partial Syndrome Generator | SOB | Syndrome Output Buffer |
| SG | Syndrome Generator | EE | Error Encoder |
| DED | Data Error Detector | DC0, 1 | Data Corrector Bytes 0, 1 |
| DE0, 1 | Data Error Bytes 0, 1 | | |
| PE | Parity Error | | |

FIGURE 1. DP8400 Block Diagram

SYSTEM WRITE (Figure 2a)

The Normal WRITE mode is mode 0 of Table III. Referring to the block diagram in Figure 9a and the timing diagram of Figure 9b, the 16 bits of data from the processor are enabled into the data input latches, DIL0 and DIL1, when the input data latch enable (DLE) is high. When this goes low, the input data is latched. The check bit generator (CG) then produces 6 parity bits, called check bits. Each parity bit monitors different combinations of the input data-bits. In the 16-bit configuration, assuming no syndrome bits are being fed in from the syndrome bus into the syndrome input latch, the 6 check bits enter the check bit output latch (COL), when the output latch enable \overline{OLE} is low, and are latched in when \overline{OLE} goes high. Whenever M2 (READ/WRITE) is low, the check bit output buffer COB always enables the COL contents onto the external check bit bus. Also the data error decoder (DED) is inhibited during WRITE so no correction can take place. Data output latches DOL0 and DOL1, when enabled with \overline{OLE} , will therefore see the contents of DIL0 and DIL1. If valid

system data is still on the data bus, a memory WRITE will write to memory the data on the data bus and the check bits output from COB. If the system has vacated the data bus, output enables ($\overline{OB0}$ and $\overline{OB1}$) must be set low so that the original data word with its 6 check bits can be written to memory.

SYSTEM READ

There are two methods of reading data: the error monitoring method (Figure 2b), and the always correct method (Figure 2c). Both require fast error detection, and the second, fast correction. With the first method, the memory data is only monitored by the E^2C^2 , and is assumed to be correct. If there is an error, the Any Error flag (AE) goes high, requiring further action from the system to correct the data. With the always correct method, the memory data is assumed to be possibly in error. Memory data is removed and the corrected, or already correct, data is output from the E^2C^2 by enabling $\overline{OB1}$ and $\overline{OB0}$. To detect an error (referring to Figures 10a and 10b) first DLE and CSLE

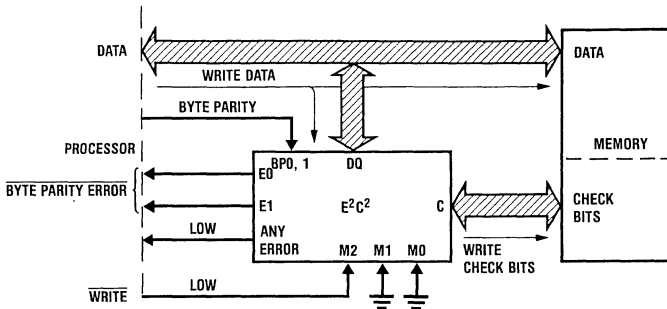


FIGURE 2a. Normal WRITE Mode with E^2C^2

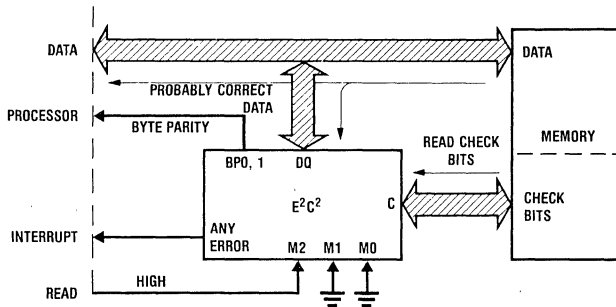


FIGURE 2b. Normal READ Mode, Error Monitoring Method with E^2C^2

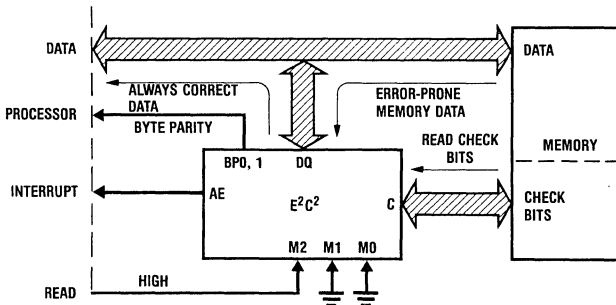


FIGURE 2c. Normal READ Mode, Always Correct Method with E^2C^2

go high to enter data bits and check bits from memory into DIL0, DOL1 and CIL. The 6 check bits generated in CG from DIL0 and DOL1 are then compared with CIL to generate syndromes on the internal syndrome bus (SG). Any bit or bits of SG that go high indicate an error to the error encoder (EE).

If data correction is required $\overline{OB0}$ and $\overline{OB1}$ must be set low (after memory data has been disabled) to enable data output buffers DOB0 and DOB1. The location of any data bit error is determined by the data error decoder (DED), from the syndrome bits. The bit in error is complemented in the DOL for correction. The other 15 bits from DED pass the DIL contents directly to the DOL, so that DOL now contains corrected data.

ERROR DETERMINATION

The three error flags, for a 16-bit example, are decoded from the internally generated syndromes as shown in Figure 3. First, if any error has occurred, the generated check bits will be different from the memory check bits, causing some of the syndrome bits to go high. By OR-ing the syndrome bits, the output will be an indication of any error.

If there is a single-data error, then (from the matrix in Table IV) it can be seen that any data error causes either 3 or 5 syndrome bits to go high. 16 AND gates decode which bit is in error and the bit in error is XOR-ed with the corresponding bit of the DIL to correct it, whereas the other 15 decoder outputs are low, causing the corresponding 15 bits in DIL to transfer to DOL directly. DOL now contains corrected data. The 16 AND gate outputs are OR-ed together causing E0 to go high, so that E0 is the single-data-error indication. If the error is a double-error, then either 2,

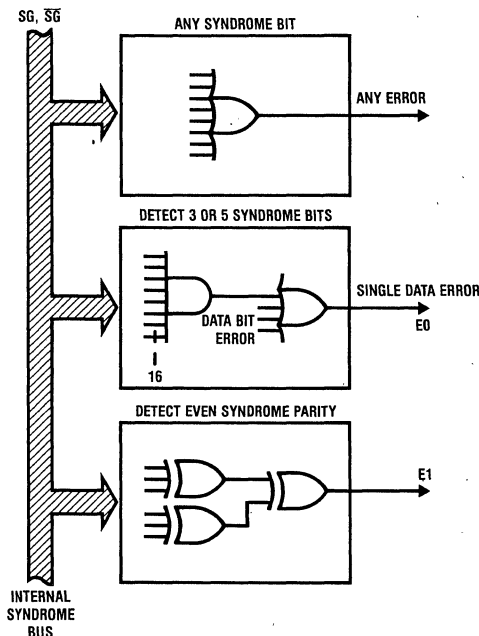


FIGURE 3. Error Encoder

4 or 6 of the syndrome bits will be high. The syndromes for two errors (including one or two check bit errors) are the two sets of syndromes for each individual error bit, XOR-ed together. By performing a parity check on the syndrome bits, flag E1 will indicate even/odd parity. If there is still an error, but it is not one of these errors, then it is a detectable triple-bit error. Some triple-bit errors are not detectable as such and may be interpreted as single-bit errors and falsely corrected as single-data errors. This is true for all standard ECC circuits using a Modified Hamming-code matrix. The DP8400 is capable, with its Rotational Syndrome Word Generator matrix, of determining all triple-bit errors using twice as many DP8400s and twice as many check bits.

ERROR FLAGS

Three error flags are provided to allow full error determination. Table I shows the error flag outputs for the different error types in Normal READ mode. If there is an error, then ANY ERROR will go high, at a time t_{DEV} (Figure 10b) after data and check bits are presented to the DP8400. The other two error flags E0 and E1 become valid t_{DE0} and t_{DE1} later.

The error flags differentiate between no error single check bit error, single data-bit error, double-bit error. Because the DP8400 can correct double errors, it is important to know that two errors have occurred, and not just a multiple-error indication. The error flags will remain valid as long as DLE and CSLE are low, or if DLE is high, and data and check bits remain valid.

BYTE PARITY SUPPORT

Some systems require extra integrity for transmission of data between the different cards. To achieve this, individual byte parity bits are transmitted with the data bits in both directions. The DP8400 offers byte parity support for up to 40 data bits. If the processor generates byte parity when transferring information to the memory, during the WRITE cycle, then each byte parity bit can be connected to the corresponding byte parity I/O pin on the DP8400, either BP0 or BP1. The DP8400 develops its own internal byte parity bits from the two bytes of data from the processor, and compares them with BP0 and BP1 using an exclusive-OR for both parities. The output of each exclusive-OR is fed to the error flags E0 and E1 as PE0 and PE1, so that a byte parity error forces its respective error flag low, as in Table II. These flags are only valid for the Normal WRITE (mode 0) and XP at 0V. The DP8400 checks and generates even byte parity.

When transferring information from the memory to the processor, the DP8400 receives the memory data, and outputs the corresponding byte parity bits on BP0 and BP1 to the processor. The processor block can then check data integrity with its own byte parity generator. If in fact memory data was in error, the DP8400 derives BP0 and BP1 from the memory input data, and not the corrected data, so when corrected data is output from the DP8400, the processor will detect a byte parity error.

If correct byte parity is required, transfer of corrected output data in the DOL to DIL will result in correct byte parity at BP0 and BP1. This can be part of a normal memory re-WRITE cycle once an error has occurred.

TABLE I. ERROR FLAGS AFTER NORMAL READ (MODE 4)

AE	E1	E0	Error Type
0	0	0	No error
1	1	0	Single check bit error
1	1	1	Single-data error
1	0	0	Double-bit error
All Others			Invalid conditions

TABLE II. ERROR FLAGS AFTER NORMAL WRITE (MODE 0)

AE	E1 (PE1)	E0 (PE0)	Error Type
0	1	1	No parity error
0	1	0	Parity error, byte 0
0	0	1	Parity error, byte 1
0	0	0	Parity error, bytes 0, 1

TABLE III. DP8400 MODES OF OPERATION

Mode	M2 (R/W)	M1	M0	\overline{OES}	Operation
0	0	0	0	X	Normal WRITE DIL → DOL, CG → COL → COB
1	0	0	1	X	Complement WRITE DIL → DOL, CIL → COL → COB
2	0	1	0	X	Diagnostic WRITE, DLE inhibited DQ8-DQ15 ⊕ CG → SOL → SOB DQ8-DQ15 → CIL → COL → COB
3	0	1	1	X	Complement data-only WRITE DIL → DOL, (CG0, 1, 4, 5, CG2, CG3) → COL → COB
4	1	0	0	X	Normal READ DIL ⊕ DE → DOL, CIL → COL
5	1	0	1	X	Complement READ DIL ⊕ DE → DOL, CIL → COL
6A	1	1	0	0	READ generated syndromes, check bit bus, error flags, SG0-SG6 → DQ0-DQ6, CIL0-CIL6 → DQ8-DQ14, E1 → DQ7, E0 → DQ15
6B	1	1	0	1	READ syndrome bus, check bit bus, error flags, SIL0-SIL6 → DQ0-DQ6, CIL0-CIL6 → DQ8-DQ14, E1 → DQ7, E0 → DQ15
7A	1	1	1	0	Generated syndromes replace with zero 0 → SIL → SG, CIL → COL, DIL ⊕ DE → DOL
7B	1	1	1	1	Generated syndromes replace SIL → SG, CIL → COL, DIL ⊕ DE → DOL

TABLE IV. DATA-IN TO CHECK BIT GENERATE, OR DATA BIT ERROR TO SYNDROME-GENERATE MATRIX (16-BIT CONFIGURATION)

											1	1	1	1	1	1	} DQ0-15	
		0	1	2	3	4	5	6	7	8	9	0	1	2	3	4		5
		GENERATE CHECK BITS →																
} GENERATED SYNDROMES	0	0	0	1	1	1	1	1	1	0	1	1	1	0	1	1	1	0
	1	0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	1
	2	1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	2*
	3	0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	3*
	4	1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	4
	5	1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	5
		4	8	9	7	5	1	3	9	E	B	D	3	C	7	F	F	0
		3	3	2	0	2	3	2	1	3	0	0	1	2	3	2	1	1
		} GENERATED CHECK BITS																

HEXADECIMAL EQUIVALENT OF SYNDROME BITS

* C2, C3 generate odd parity

MODES OF OPERATION

There are three mode-control pins, M2, M1 and M0, offering 8 major modes of operation, according to Table III.

M2 is the READ/WRITE control. In normal operation, mode 0 is Normal WRITE and mode 4 is Normal READ. By clamping M0 and M1 low, and setting M2 low during WRITE and high during READ, the DP8400 is very easy to use for normal operation. The other modes will be covered in later sections.

16-Bit Configuration

The first two rows on top of the check bit generate matrix (Table IV) indicate the data position of DQ0 to DQ15. The left side of the matrix, listed 0 to 5, corresponds to syndromes S0 to S5. S0 is the least significant syndrome bit. There are two rows of hexadecimal numbers below the matrix. They are the hex equivalent of the syndrome patterns. For example, syndrome pattern in the first column of the matrix is 001011. Its least significant four bits (0010) equal hexadecimal 4, and the remaining two bits (11) equal hexadecimal 3.

Check bit generation is done by selecting different combinations of data bits and generating parities from them. Each row of the check bit generate matrix corresponds to the generation of a check bit numbered on the right hand side of the matrix, and the ones in that row indicate the selection of data bits.

The following are the check bit generate equations for 16-bit wide data words:

$$CG0 = DQ2 \oplus DQ3 \oplus DQ4 \oplus DQ5 \oplus DQ6 \oplus DQ7 \oplus DQ9 \oplus DQ10 \oplus DQ11 \oplus DQ13 \oplus DQ14 \oplus DQ15$$

$$CG1 = DQ3 \oplus DQ6 \oplus DQ8 \oplus DQ9 \oplus DQ11 \oplus DQ13 \oplus DQ14 \oplus DQ15$$

$$*CG2 = DQ0 \oplus DQ3 \oplus DQ4 \oplus DQ8 \oplus DQ10 \oplus DQ12 \oplus DQ13 \oplus DQ14 \oplus DQ15 \oplus 1$$

$$*CG3 = DQ1 \oplus DQ2 \oplus DQ7 \oplus DQ8 \oplus DQ9 \oplus DQ10 \oplus DQ12 \oplus DQ14 \oplus DQ15 \oplus 1$$

$$CG4 = DQ0 \oplus DQ1 \oplus DQ5 \oplus DQ7 \oplus DQ8 \oplus DQ11 \oplus DQ13 \oplus DQ15$$

$$CG5 = DQ0 \oplus DQ1 \oplus DQ2 \oplus DQ4 \oplus DQ5 \oplus DQ6 \oplus DQ8 \oplus DQ12 \oplus DQ13 \oplus DQ14$$

*CG2 and CG3 are odd parities.

The following error map (Table V) depicts the relationship between all possible error conditions and their associated syndrome patterns. For example, if a syndrome pattern is S0 - 5 = 111101, data bit 14 is in error.

Figure 4 shows how to connect one DP8400 in a 16-bit configuration, in order to detect and correct single or double

bit errors. For a Normal WRITE, processor data is presented to the DP8400, where it is fed through DIL0 and DIL1 to the check bit generator. This generates 6 parity bits from different combinations of data bits, according to Table IV. The numbers in the row below the table are the hexadecimal equivalent of the column bits (with bits 6, 7 low). A '1' in any row indicates that the data bit in that column is connected to the parity generator for that row. For example, check bit 1 generates parity from data bits 3, 6, 8, 9, 11, 13, 14, and 15.

Check bits 0, 1, 4, 5, and 6 generate even parity, and check bits 2 and 3 generate odd parity. This is done to insure that a total memory failure is detected. If all check bits were even parity, then all zeros in the data word would generate all check bits zero and a total memory failure would not be detected when a memory READ was performed. Now all-zero-data bits produce C2 and C3 high and a total memory failure will be detected. When reading back from the same location, the memory data bits (possibly in error) are fed to the same check bit generator, where they are compared to the memory check bits (also possibly in error) using 6 exclusive-OR gates. The outputs of the XORs are the syndrome bits, and these can be determined according to Table IV for one data bit error. For example, an error in bit 2 will produce the syndrome word 101001 (for S5 to S0 respectively). The syndrome word is decoded by the error encoder to the error flags, and the data-error decoder to correct a single data bit error. Assuming the memory data has been latched in the DIL, by making DLE go low, memory data can be disabled. Then by setting OB0 and OB1 low, corrected data will appear on the data bus. The syndromes are available as outputs on pins S0-5 when OES is low. It is also possible to feed in syndromes to SIL when OES is high and CSLE goes high. This can be useful when using the Error Management Unit shown in Figure 4. C6 and S6 are not used for 16 bits. It is safe therefore to make C6 appear low, through a 2.7 kΩ resistor to ground. The same applies for S6 if syndromes are input to the DP8400. If OES is permanently low, S6 may be left open.

Any 16-bit memory correct system using the DP8400 without syndrome inputs must keep the OES pin grounded, then all the syndrome I/O pins may be left open. The reason for this is that the DP8400 resets the syndrome input latch at power up. If the OES pin is grounded, the syndrome input latch will remain reset for normal operations.

The parameter t_{NMR} (see Figure 10b), new mode recognized time, is measured from M2 (changing from READ to WRITE) to the valid check bits appearing on the check bit bus, provided the OLE was held low.

TABLE V. SYNDROME DECODE TO BIT IN ERROR FOR 16-BIT DATA WORD

Syndrome Bits		S0	0	1	0	1	0	1	0	1	0	1	0	1	0	1	
S1		0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1
S2		0	0	0	0	1	1	1	1	0	0	0	1	1	1	1	1
S3		0	0	0	0	0	0	0	0	1	1	1	1	1	1	1	1
S5 S4																	
0	0	NE	C0	C1	D	C2	D	D	3	C3	D	D	9	D	10	T	D
0	1	C4	D	D	11	D	T	T	D	D	7	T	D	T	D	D	15
1	0	C5	D	D	6	D	4	T	D	D	2	T	D	12	D	D	14
1	1	D	5	T	D	0	D	D	13	1	D	D	T	D	T	8	D

NE = no error

Cn = check bit n in error

T = three errors detected

Number = single data bit in error

D = two bits in error

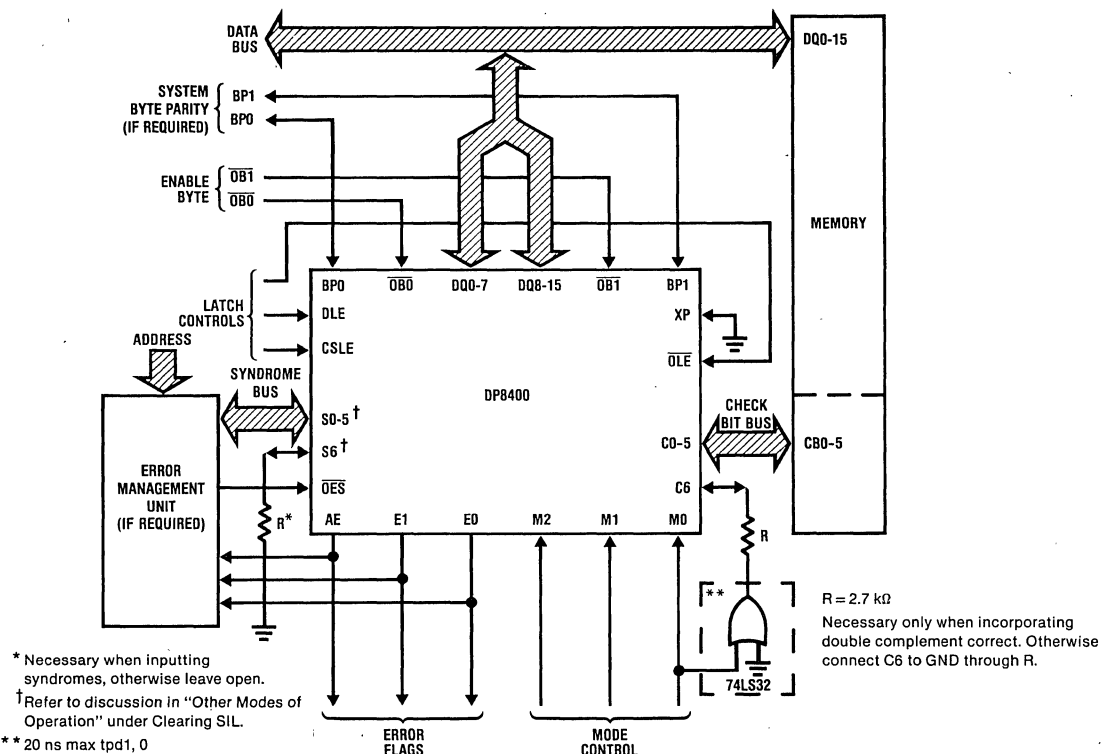


FIGURE 4. 16-Bit Configuration Using One DP8400

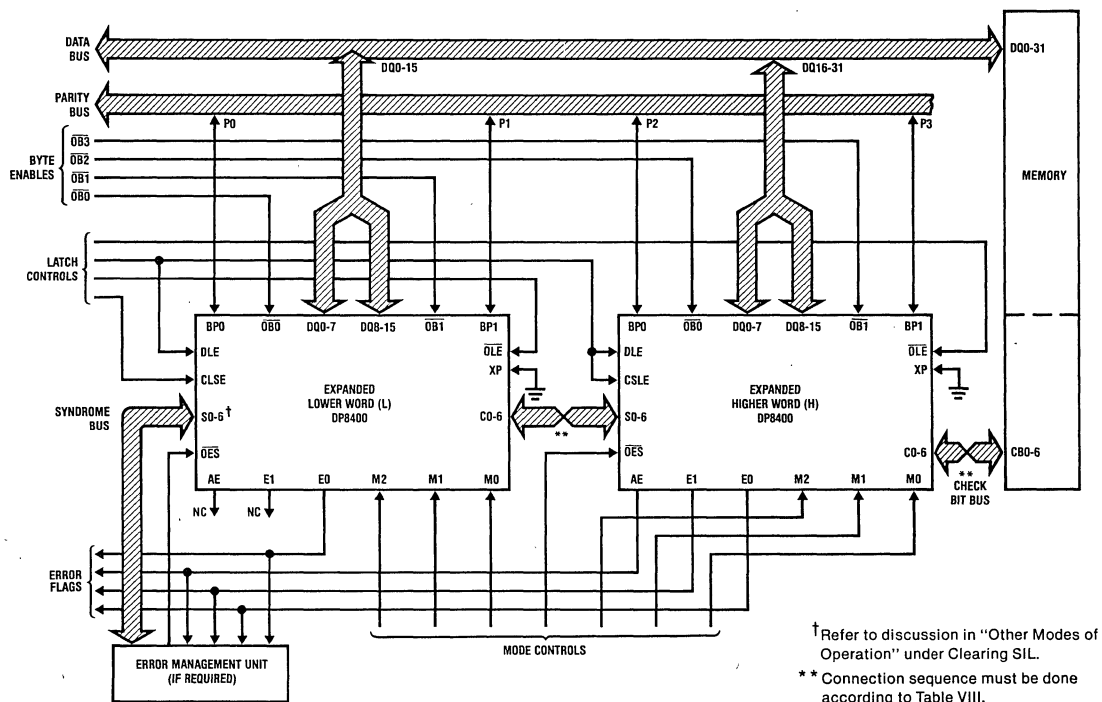


FIGURE 5. 32-Bit Error Detection and Correction

The parameter t_{MCR} (see Figure 10b), mode change recognized time, is measured from M2 (changing from WRITE to READ) when both E1 and E2 become invalid. This is required when a memory correcting system employs the DP8400 with byte parity checking. The E1 and E2 pins flag the byte parity error in a memory WRITE cycle. When the DP8400 switches to a subsequent memory READ cycle, it requires t_{MCR} for E1 and E2 to be switched to flag any READ error(s).

EXPANDED OPERATION

32-Bit Configuration

Figure 5 shows how to connect two DP8400s in cascade to detect single and double-bit errors, and to correct single-data errors. The same circuit will also correct double-bit errors once a double-error has been detected, provided at least one error is a hard error. The lower chip L is in effect a slave to the higher chip H, which controls the memory check bits and error reporting. The check bit bus of L is re-ordered and connected to the syndrome bus of H, as shown in Figure 5.

In a Normal WRITE mode, referring to Figures 13a, 13b, and 13c, the 6 check bits generated from the lower 16 bits (CGL) are transferred via the COL to the COB of L, provided OLE is high and M2 (R/W) of L is low. These partial check bits from L then appear at SIL of H, so that with CSLE high, they combine with the 6 check bits generated in H with an overlap of one bit, to produce 7 check bits. With M2 (R/W) of H low, these 7 check bits are output from COB to memory.

A READ cycle may consist of DETECT ONLY or DETECT THEN CORRECT, depending on the system approach. In both approaches, L writes its partial check bits, CGL, to H as in WRITE mode. H develops the syndrome bits from CGL, CGH and the 7 check bits read from memory in CIL. H then outputs from its error encoder (EE) if there is an error. If corrected data is required, H already knows if it has a single-data error from its syndrome bits, but if not, it must transfer partial syndromes back to L. These partial syndromes PSH, (CGH XOR-ed with CIL), are stored in SOL of H. L must therefore change modes from WRITE to READ, while H outputs the partial syndromes from its SOB by setting OES low. The partial syndromes are fed into CIL of L and XOR-ed with CGL to produce syndrome bits at SGL. The data error decoder, DED, then corrects the error in L. The DED of H will already have corrected an error in the higher 16 bits. Only one error in 32 bits can be corrected as a single-data error, the chip with no error does not change the contents of its DIL when it is enabled in DOL. Table VI shows the 3 error flags of H, which become valid during the DETECT cycle. E0 of L becomes valid during the CORRECT cycle, so that the 4 flags provide complete error reporting.

TABLE VI. ERROR FLAGS AFTER NORMAL READ (32-BIT CONFIGURATION)

AE (H)	E1 (H)	E0 (H)	E0 (L)*	Error Type
0	0	0	0	No error
1	1	0	0	Single-check bit error
1	1	1	0	Single-data bit error (H)
1	1	0	1	Single-data bit error (L)
1	0	0	0	Double-bit error
All Others				Invalid conditions

* E0 (L) is valid after transfer of partial syndromes from higher to lower

Equations for 32-bit expansion:

$$t_{DCB32} = t_{DCB16} + t_{SCB16}$$

$$t_{DEV32} = t_{DCB16} + t_{SEV16}$$

$$t_{DCD32} (\text{High Chip}) = t_{DCB16} + t_{SCD16}$$

$$t_{DCD32} (\text{Low Chip}) = t_{DCB16} + t_{BR}^* + t_{CCD16}$$

* t_{BR}: Bus reversing time (25 ns)

32-Bit Matrix

Table VII shows a 32-bit matrix using two DP8400s in cascade as in Figure 5. This is one of 12 matrices that work for 32 bits. The matrix for bits 0 to 15 (lower chip) is the matrix of Table IV for 16-bit configuration, with row 6 always '0'. The matrix for bits 16 to 31 (higher chip) uses the same row combinations but interchanged, for example, the 3rd row (row 2) of L matrix is the same as the 6th row (row 5) of the H matrix. This means row 5 of H is in fact check bit 2 of H. Thus, the 6th row (row 5) combines generated check bit 5 (CG5) of L and generated check bit 2 of H. Check bit 5 of L therefore connects to the syndrome bit 2 (CG2) of H, and the composite generated check bit is written to check bit 2 of memory. Thus C2 performs a parity check on bits 0, 1, 2, 4, 5, 6, 8, 12, 13, 14, of L, and bits 16, 19, 20, 24, 26, 28, 29, 30, 31, of H. CG2 and CG3 generate odd parity, so that CG5 of L generates even parity which combines with CG2 of H generating odd parity. CG3 of L and CG3 of H both generate odd parity causing C3 to memory to represent even parity. Only 6 check bits are generated in each chip, the 7th (CG6) is always zero with XP grounded. Thus CG6 of L combines with CG0 of H so that C0 to memory is the parity of bits 18, 19, 20, 21, 22, 23, 25, 26, 27, 29, 30, 31. Similarly C6 to memory is only CG2 of L. The 7 composite generated check bits of H can now be written to memory.

When reading data and check bits from memory, CG6-CG0 of L are combined with CG6-CG0 of H in the same combination as WRITE. Memory check bits are fed into C6-C0 of H and compared with the 7 combined parity bits

TABLE VII. DATA BIT ERROR TO SYNDROME-GENERATE MATRIX (32-BIT CONFIGURATION)

SYNDROMES	L																H																HEX		
	0	1	2	3	4	5	6	7	8	9	0	1	2	3	4	5	6	7	8	9	0	1	2	3	4	5	6	7	8	9					
0	0	0	1	1	1	1	1	1	0	1	1	1	0	1	1	0	0	0	1	0	1	0	1	1	0	1	0	1	1	1	1	1			
1	0	0	0	1	0	0	1	0	1	0	1	0	1	1	1	1	1	1	0	1	1	1	0	1	0	0	0	0	1	1	1	0	5		
2	1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	6			
3	0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	0	1	1	0	0	0	1	1	1	0	1	0	1	0	1	1	3		
4	1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	4		
5	1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	2		
6	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0		
	4	8	9	7	5	1	3	9	E	B	D	3	C	7	F	F	2	A	A	1	2	2	3	8	B	9	8	1	A	3	B	9	0		
	3	3	2	0	2	3	2	1	3	0	0	1	2	3	2	1	3	1	4	6	6	5	4	5	3	4	6	5	2	7	6	7	1		

* CG2, CG3 generate odd parity

TABLE VIII. CHECK BIT PORT TO SYNDROME PORT INTERCONNECTIONS FOR EXPANSION TO 32 BITS

		L	L	H	H		
		S	C	S	C		
Syndrome I/O to Management	S0	0	0	1	1	C0	Check Bit I/O to Memory
	S1	1	1	5	5	C1	
	S2	2	2	6	6	C2	
	S3	3	3	3	3	C3	
	S4	4	4	4	4	C4	
	S5	5	5	2	2	C5	
	S6	6	6	0	0	C6	

TABLE IX. SYNDROME DECODE TO BIT IN ERROR FOR 32-BIT DATA WORD

Syndrome Bits	S0	0	1	0	1	0	1	0	1	0	1	0	1	0	1				
	S1	0	0	1	1	0	0	1	1	0	0	1	1	0	0				
	S2	0	0	0	0	1	1	1	1	0	0	0	0	1	1				
	S3	0	0	0	0	0	0	0	0	1	1	1	1	1	1				
	S6	S5	S4																
	0	0	0	NE	C0	C1	D	C2	D	D	3	C3	D	D	9	D	10	T	D
	0	0	1	C4	D	D	11	D	T	T	D	D	7	17	D	T	D	D	15
	0	1	0	C5	D	D	6	D	4	T	D	D	2	28	D	12	D	D	14
	0	1	1	D	5	16	D	0	D	D	13	1	D	D	24	D	T	8	D
	1	0	0	C6	D	D	22	D	T	T	D	D	25	18	D	T	D	D	T
	1	0	1	D	27	21	D	T	D	D	T	23	D	D	T	D	T	T	D
	1	1	0	D	19	20	D	T	D	D	T	26	D	D	30	D	T	T	D
	1	1	1	T	D	D	29	D	T	T	D	D	31	T	D	T	D	D	T

NE = no error Cn = check bit n in error T = three errors detected
 Number = single data bit in error D = two bits in error

in H, to produce 7 syndrome bits S6-S0. H can now determine if there is any error, and if it has a single-data error, it can locate it and correct it without transferring partial syndromes to L. As an example of a DETECT cycle, CG5 of L combines with CG2 of H and is compared in H with memory check bit 2.

If L is now set to mode 4, Normal READ, and \overline{OES} of H is set low, the partial syndromes of H (CG6-CG0 of H XOR-ed with C6-C0 of H) are transferred and shifted to L. L receives these partial syndromes (S6-S0 of H) as check bit inputs C2, C1, C4, C3, C5, C0, C6 respectively, and compares them with CG6-CG0 respectively, to produce syndrome bits S6-S0. L now decodes these syndromes to correct any single-data error in data bits 0 to 15. For example, partial syndrome bit 2 of H combines with generated check bit 5 of L to produce syndrome bit 5 in L. An error in data bit 10 will create syndrome bits in L as 0001101 from S6-S0, and these will appear on S6-S0 of L with \overline{OES} low. An error in H will appear as per the H matrix. For example, an error in bit 16 will cause S6-S0 of L to be 0110010.

If \overline{OES} of L is set low, this syndrome combination appears on pins S6 to S0. For errors in bits 0 to 15, the syndrome outputs will be according to Table VII. For errors in bits 16 to 31, the syndrome outputs from L will still be according to Table VII due to the shifting of partial syndrome bits from H to L. The syndrome outputs from L are unique for each of the possible 32 bits in error.

If there is a check bit error, only one syndrome bit will be high. For example, if C5 is in error, then S1 of L will be high. For double-errors, an even number of syndrome bits will be high, derived from XOR-ing the two single-bit error syndromes. As mentioned previously, this is only one of the 12 approaches to connecting two chips for 32 bits, 6 of which are mirror images.

Table VIII depicts the exact connection for 32-bit expansion. LS equals syndrome bits of L. LC equals check bits of L. HS equals syndrome bits of H. HC equals check bits of H. Syndrome bits S0 to S6 of L are connected to system syndrome bits S0 to S6. LC and HS columns are lined together showing the check bit port of L connected to the syndrome port of H in the exact sequence as shown in Table VIII. For example, check bit C0 of L is connected to the syndrome bit S1 of H, and check bit C6 of L is connected to the syndrome bit S0 of H. Check bits of H are connected to the system check bits in the order shown. Check bit C1 of H is connected to the system check bit C0.

Expansion for Data Words Requiring 8 Check Bits

For 16-bit and 32-bit configurations, XP is set permanently low. In 48-bit or 64-bit configurations, XP is either set permanently to V_{CC} or left open, according to Table X, to provide 8 check bits and syndrome bits.

TABLE X. XP: EXPANSION STATUS

XP	Status	Data Bus
0V	BP0 and BP1 are byte parity I/O CG6 = 0	< 40 Bits
Open	No byte parity I/O, CG6 and CG7 = word parity	≥ 40 Bits
V_{CC}	No byte parity I/O, CG6 and CG7 = 0	≥ 40 Bits

48-Bit Expansion

Three DP8400s are required for 48 bits, with the higher chip using all 8 of its check bits to the memory. No byte parity is available for 48 or 64 bits. XP of all three chips must be at V_{CC} . The three chips are connected in cascade

TABLE XI. CHECK BIT PORT TO SYNDROME PORT INTERCONNECTIONS FOR EXPANSION TO 48 BITS

		LL	LL	LH		LH	HL		HL	
		S	C	S		C	S		C	
Syndrome I/O to Management	S0	0	0	1		1	6		6	C0
	S1	1	1	5		5	1		1	C1
	S2	2	2	6		6	4		4	C2
	S3	3	3	3		3	7		7	C3
	S4	4	4	4		4	2		2	C4
	S5	5	5	2		2	3		3	C5
	S6	6	6	0		0	5		5	C6
	S7	7	7	7		7	0		0	C7
										Check Bit I/O to Memory

For example: S0 of LL is connected to system syndrome S0. C0 of LL is connected to S1 of LH. C1 of LH is connected to S6 of HL. C6 of HL is connected to system check bit C0.

TABLE XII. SYNDROME DECODE TO BIT IN ERROR FOR 48-BIT DATA WORD

Syndrome Bits	S0	0	1	0	1	0	1	0	1	0	1	0	1	0	1		
	S1	0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1
	S2	0	0	0	0	1	1	1	1	0	0	0	0	1	1	1	1
	S3	0	0	0	0	0	0	0	0	1	1	1	1	1	1	1	1
	S7 S6 S5 S4																
	0 0 0 0	NE	C0	C1	D	C2	D	D	3	C3	D	D	9	D	10	T	D
	0 0 0 1	C4	D	D	11	D	T	T	D	D	7	17	D	T	D	D	15
	0 0 1 0	C5	D	D	6	D	4	T	D	D	2	28	D	12	D	D	14
	0 0 1 1	D	5	16	D	0	D	D	13	1	D	D	24	D	T	8	D
	0 1 0 0	C6	D	D	22	D	T	T	D	D	25	18	D	T	D	D	T
	0 1 0 1	D	27	21	D	32	D	D	T	23	D	D	T	D	T	T	D
	0 1 1 0	D	19	20	D	33	D	D	T	26	D	D	30	D	T	T	D
	0 1 1 1	44	D	D	29	D	T	40	D	D	31	T	D	T	D	D	T
	1 0 0 0	C7	D	D	T	D	T	43	D	D	T	T	D	T	D	D	T
	1 0 0 1	D	T	35	D	T	D	D	T	T	D	D	T	D	T	T	D
	1 0 1 0	D	T	41	D	39	D	D	T	T	D	D	T	D	T	T	D
	1 0 1 1	42	D	D	T	D	T	47	D	D	T	T	D	T	D	D	T
	1 1 0 0	D	T	38	D	37	D	D	T	T	D	D	T	D	T	T	D
	1 1 0 1	36	D	D	T	D	T	45	D	D	T	T	D	T	D	D	T
	1 1 1 0	34	D	D	T	D	T	T	D	D	T	T	D	T	D	D	T
	1 1 1 1	D	T	46	D	T	D	D	T	T	D	D	T	D	T	T	D

NE = no error
 Number = single data bit in error
 Cn = check bit n in error
 D = two bits in error
 T = three errors detected

as in Figure 6, but with the HH chip removed. The error flags are as Table XV, but with AE (HH) and E1 (HH) becoming AE (HL) and E1 (HL), and E0 (HH) removed.

48-Bit Matrix

The matrix for 48 bits is that for 64 bits shown (in Table XVI) but only using bits 0 to 47. This is one of many matrices for 48-bit expansion using the basic 16-bit matrix. The matrix shown uses 2 zeroes for CG6 and CG7, for all three chips, with XP set to VCC. Other matrices may use CG6 and CG7 as word parity with XP open.

64-Bit Expansion

There are two basic methods of expansion to 64 bits, both requiring 8 check bits to memory, and four DP8400s. One is the cascade method of Figure 6, requiring no extra ICs. With this method partial check bits have to be transferred through three chips in the WRITE or DETECT mode, and partial syndrome bits transferred back through three chips in CORRECT mode. This method is similar to Figure 5, 32-bit approach. The connections between the

check bit bus and syndrome bus for each of the chip pairs are shown in Table XIII.

The error flags of HH are valid during the DETECT cycle as in Table XV, and the other error flags are valid during the CORRECT cycle.

A faster method of 64-bit expansion shown in Figure 7 requires a few extra ICs, but can WRITE in 57 ns, DETECT in 57 ns or DETECT THEN CORRECT in 116 ns. In the WRITE mode, all four sets of check bits are combined externally in the 8 74S280 parity generators. These generate 8 composite check bits from the system data, which are then enabled to memory. In the DETECT mode, again 8 composite check bits are generated, from the memory data this time, and compared with the memory check bits to produce 8 external syndrome bits. These syndrome bits may be OR-ed to determine if there is any error. By making the 74S280 outputs SYNDROMES, then any bit low causes the 74S30 NAND gate to go high, giving any error indication. To correct the error, these syndrome bits are fed re-ordered into SIL of each DP8400 now set to mode 7B. This enables the syndromes directly to SG and then

DED of each chip. One chip will output corrected data, while the other three output non-modified data (but still correct).

Equations for fast 64-bit expansion:

$$t_{DCB64} = t_{DCB16} + t_{pd}(74S280) + t_{pd}(74S240)$$

$$t_{DEV64} = t_{DCB16} + t_{pd}(74S280) + t_{pd}(74S30)$$

$$t_{DCD64} = t_{DCB16} + t_{pd}(74S280) + t_{pd}(74ALS533) + t_{SCD16}$$

64-Bit Matrix

With the 64-bit matrix shown in Table XVI, it is necessary to set at least one chip with CG6, CG7 non-zero. The highest chip, connected to data bits 48 to 63, has XP set open, so that its CG6 and CG7 are word parity. The syndrome word of the highest chip will now have either 5 or 7 syndrome bits high, but inside the chip CG6 and CG7 remove two of these in a READ so that the chip sees the normal 3 or 5 syndrome bits.

TABLE XIII. CHECK BIT PORT TO SYNDROME PORT INTERCONNECTIONS FOR EXPANSION TO 64 BITS

	LL S	LL C	LH S	LH C	HL S	HL C	HH S	HH C	Check Bit I/O to Memory						
									S0	S1	S2	S3	S4	S5	S6
S0	0	0	1	1	6	6	7	7	C0						
S1	1	1	5	5	1	1	0	0	C1						
S2	2	2	6	6	4	4	1	1	C2						
S3	3	3	3	3	7	7	2	2	C3						
S4	4	4	4	4	2	2	3	3	C4						
S5	5	5	2	2	3	3	4	4	C5						
S6	6	6	0	0	5	5	5	5	C6						
S7	7	7	7	7	0	0	6	6	C7						

For example: S0 of LL is connected to system syndrome S0. C0 of LL is connected to S1 of LH. C1 of LH is connected to S6 of HL. C6 of HL is connected to S7 of HH. C7 of HH is connected to system check bit C0.

TABLE XIV. SYNDROME DECODE TO BIT IN ERROR FOR 64-BIT DATA WORD

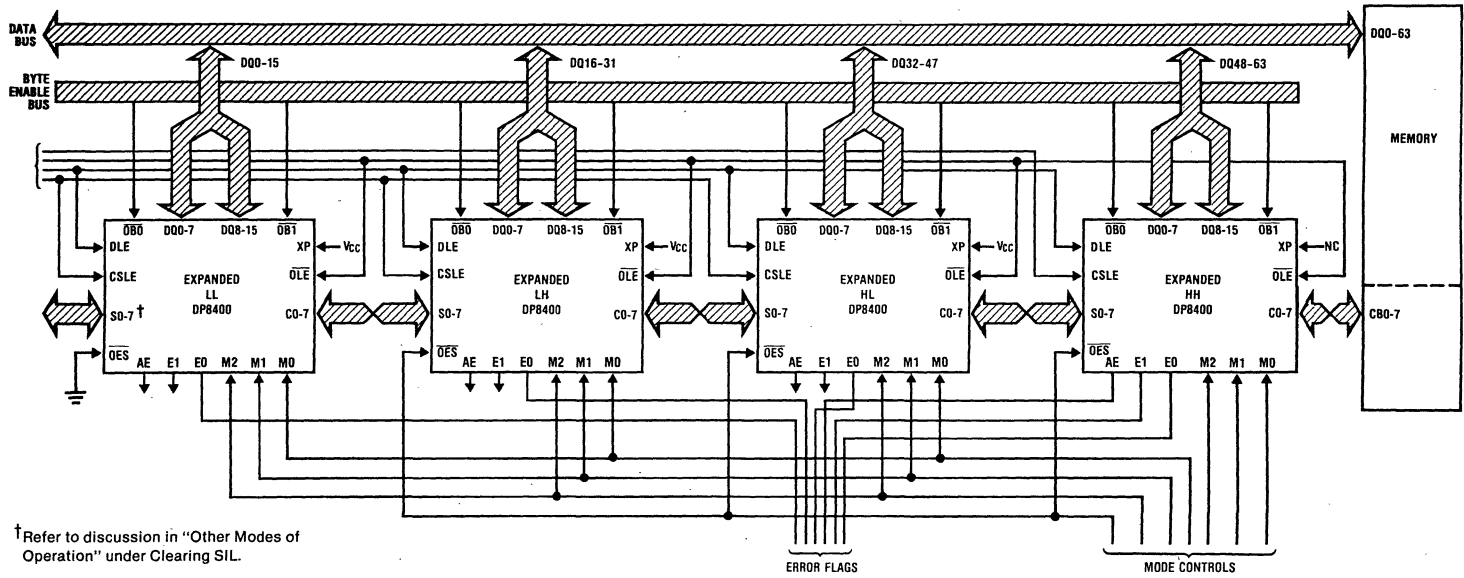
Syndrome Bits	S0	S1	S2	S3	S7	S6	S5	S4	NE	C0	C1	D	C2	D	D	3	C3	D	D	9	D	10	T	D
0 0 0 0	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1
0 0 0 1	0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1
0 0 1 0	0	0	0	0	1	1	1	1	0	0	0	0	1	1	1	1	1	1	1	1	1	1	1	1
0 0 1 1	0	0	0	0	0	0	0	0	0	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1
0 1 0 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0 1 0 1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0 1 1 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
0 1 1 1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1 0 0 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1 0 0 1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1 0 1 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1 0 1 1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1 1 0 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1 1 0 1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1 1 1 0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
1 1 1 1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0

NE = no error Cn = check bit n in error T = three errors detected
 Number = single data bit in error D = two bits in error

TABLE XV. ERROR FLAGS AFTER NORMAL READ (ANY 64-BIT CONFIGURATION)

AE (HH)	E1 (HH)	E0 (HH)	E0 (HL)	E0 (LH)	E0 (LL)	Error Type
0	0	0	0	0	0	No error
1	1	0	0	0	0	Single-check bit error
1	1	1	0	0	0	Single-data bit error in HH
1	1	0	1	0	0	Single-data bit error in HL
1	1	0	0	1	0	Single-data bit error in LH
1	1	0	0	0	1	Single-data bit error in LL
1	0	0	0	0	0	Double-error





† Refer to discussion in "Other Modes of Operation" under Clearing SIL.

FIGURE 6. Cascade Expansion Using No Extra ICs (64-Bit Configuration)

TABLE XVI. DATA BIT ERROR TO SYNDROME-GENERATE MATRIX (64-BIT CONFIGURATION)

LL											LH											HL											HH											DQ0-63											
0 1 2 3 4 5 6 7 8 9 0 1 2 3 4 5											1 1 1 1 1 1 1											1 1 1 1 2 2 2 2 2 2 2 2 2 2 3 3											3 3 3 3 3 3 3 3 4 4 4 4 4 4 4 4											4 4 5 5 5 5 5 5 5 5 5 5 5 5 6 6 6 6											
0 0 1 1 1 1 1 1 0 1 1 1 0 1 1 1											0 0 0 1 0 0 1 0 1 1 1 0 1 0 1 1 1											0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0											1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1											7											
0 0 0 1 0 0 1 0 1 1 0 1 0 1 1 1											1 1 1 0 1 1 1 0 1 1 0 0 0 1 1 1 0											0 0 0 1 0 0 1 0 1 1 0 1 0 1 1 1											0 0 1 1 1 1 1 1 0 1 1 1 0 1 1 1											0											
1 0 0 1 1 0 0 0 1 0 1 0 1 1 1 1											0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0											1 1 0 0 0 1 0 1 1 0 0 1 0 1 0 1											0 0 0 1 0 0 1 0 1 1 0 1 0 1 1 1											1											
0 1 1 0 0 0 0 1 1 1 1 0 1 0 1 1											0 1 1 0 0 0 0 1 1 1 1 0 1 0 1 1											0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0											1 0 0 1 1 0 0 0 1 0 1 0 1 1 1 1											2											
1 1 0 0 0 1 0 1 1 0 0 1 0 1 0 1											1 1 0 0 0 1 0 1 1 0 0 1 0 1 0 1											1 0 0 1 1 0 0 0 1 0 1 0 1 1 1 1											0 1 1 0 0 0 0 1 1 1 0 1 0 1 1 1											3											
1 1 1 0 1 1 1 0 1 0 0 0 1 1 1 0											1 0 0 1 1 0 0 0 1 0 1 0 1 1 1 1											0 1 1 0 0 0 0 1 1 1 1 0 1 0 1 1											1 1 0 0 0 1 0 1 1 0 0 1 0 1 0 1											4											
0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0											0 0 1 1 1 1 1 1 0 1 1 0 1 1 1											1 1 1 0 1 1 1 0 1 0 0 0 1 1 1 0											1 1 1 0 1 1 1 0 1 0 0 0 1 1 1 0											5											
0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0											0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0											0 0 1 1 1 1 1 1 0 1 1 0 1 1 1											1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1											6											
4 8 9 7 5 1 3 9 E B D 3 C 7 F F											2 A A 1 2 2 3 8 B 9 8 1 A 3 B 9											4 4 0 2 0 4 2 4 6 2 0 6 0 6 2 6											9 1 3 F B 3 7 3 D 7 B 7 9 F F F											0 HEX											
3 3 2 0 2 3 2 1 3 0 0 1 2 3 2 1											3 1 4 6 6 5 4 5 3 4 6 5 2 7 6 7											5 6 E 9 D C C A 7 A B 8 7 D F B											E F D 8 C E C B F 9 9 A D E D B											1											

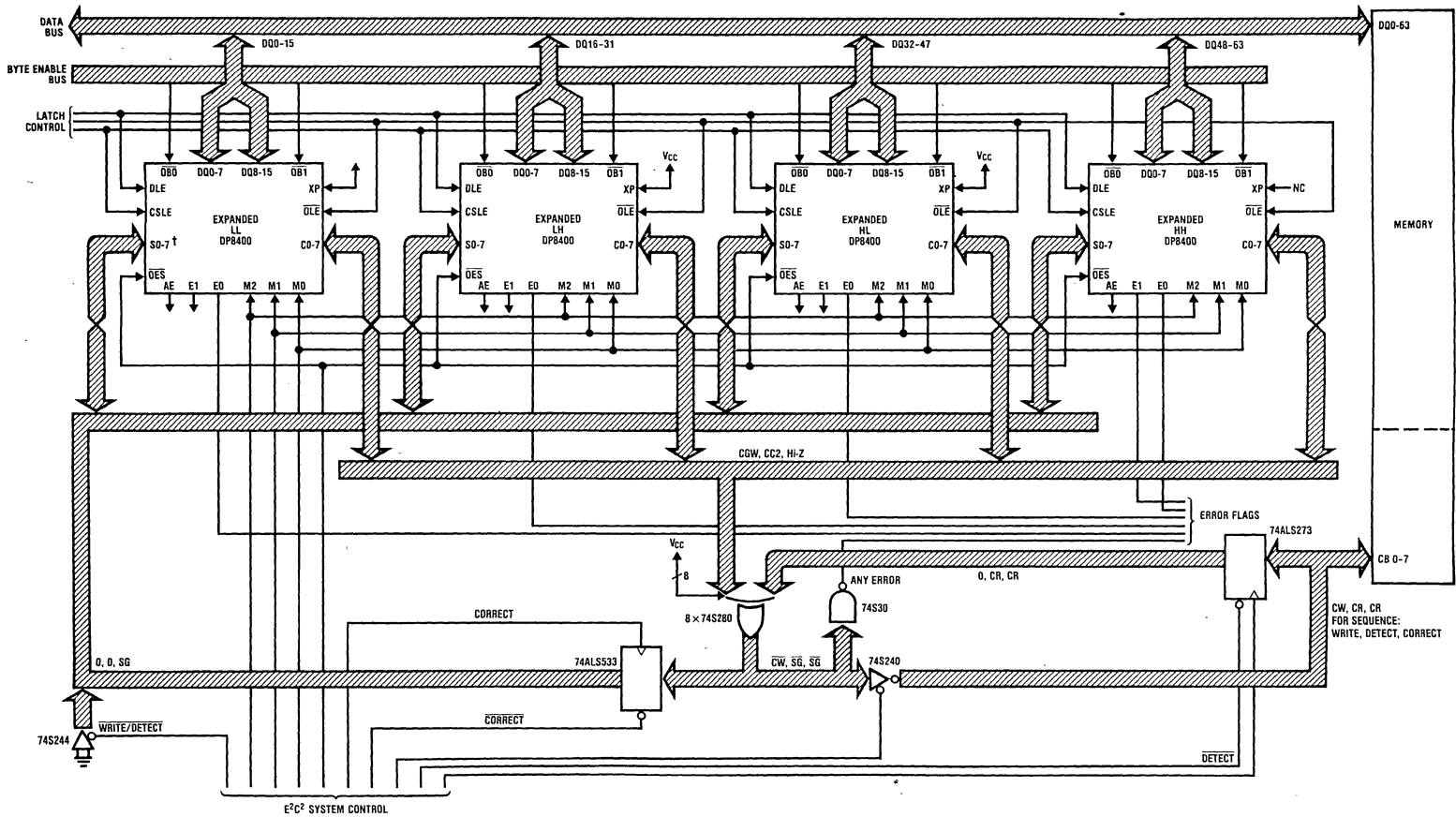


FIGURE 7. Parallel Expansion (Fast 64-Bit Configuration)

OTHER MODES OF OPERATION

Double Error Correction, using the Double-Complement Approach

The DP8400 can be made to correct two errors, using no extra ICs or check bits, if at least one of the two errors detected is a hard error. This does require an extra memory WRITE and READ. Nevertheless, if a permanent failure exists, and an additional error occurs (creating two errors), both errors can be corrected, thereby saving a system crash.

Once a double error has been detected, the system puts the DP8400 in COMPLEMENT mode by setting M0 high. First a WRITE cycle is required and M2 is set low, putting the chip in mode 1, Table III, (COMPLEMENT WRITE), so that the contents of DIL are complemented into DOL, and the contents of CIL complemented into COL. OB0 and OB1 are set low so that complemented data and check bits can be written back to the same location of memory. Writing back complemented data to a location with a hard

error forces the error to repeat itself. For example, if cell N of a particular location is jammed permanently high, and a low is written to it, a high will be read. However, when the data is complemented a low is again written, so that a high is read back for the second time. After a second READ (this second READ is a COMPLEMENT READ) of the location, data and check bits from the memory are re-complemented, so that bit N now contains a low. In other words, the error in bit N has corrected itself, while the other bits are true again. If there are two hard errors in a location, both are automatically corrected and the DP8400 detects no error on COMPLEMENT READ, as in Figure 8a. Figure 8b also shows that if one error is soft, the hard error will disappear on the second READ and the DP8400 corrects the soft error as a single-error. Therefore, in both cases, the DOL contains corrected data, ready to be enabled by OB0 and OB1. A WRITE to memory at this stage removes the complemented data written at the start of the sequence.

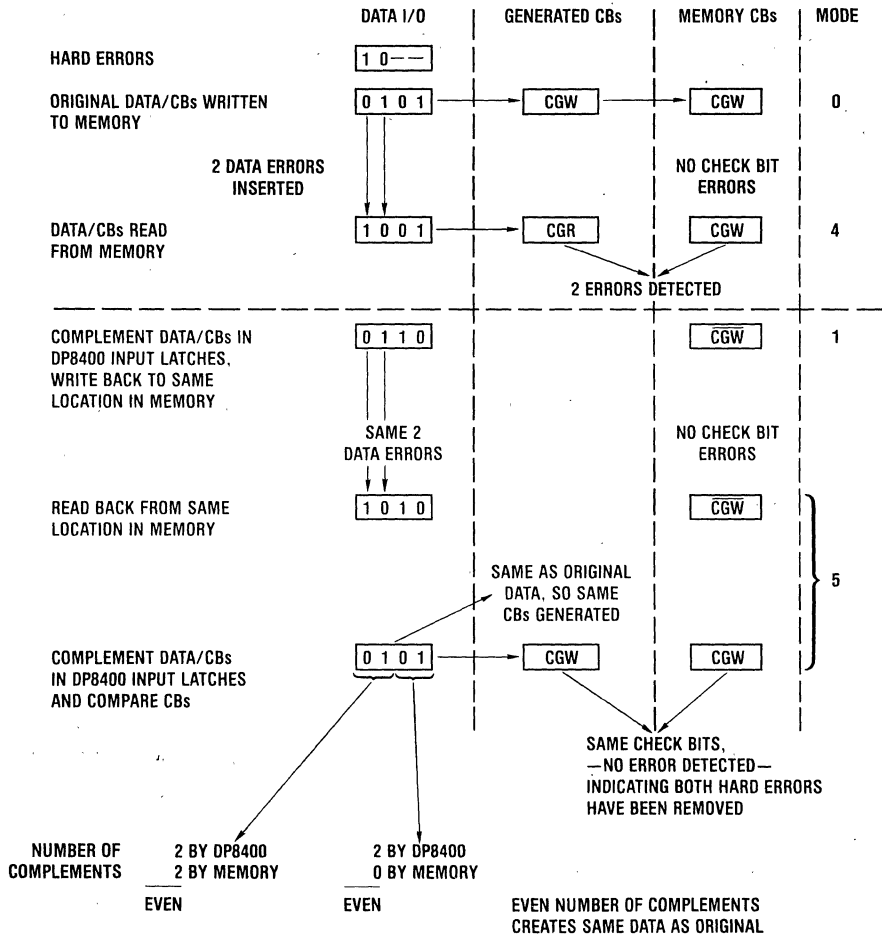


FIGURE 8a. Double Error Correct Complement Hard Error Method — 2 Hard Errors in Data Bits

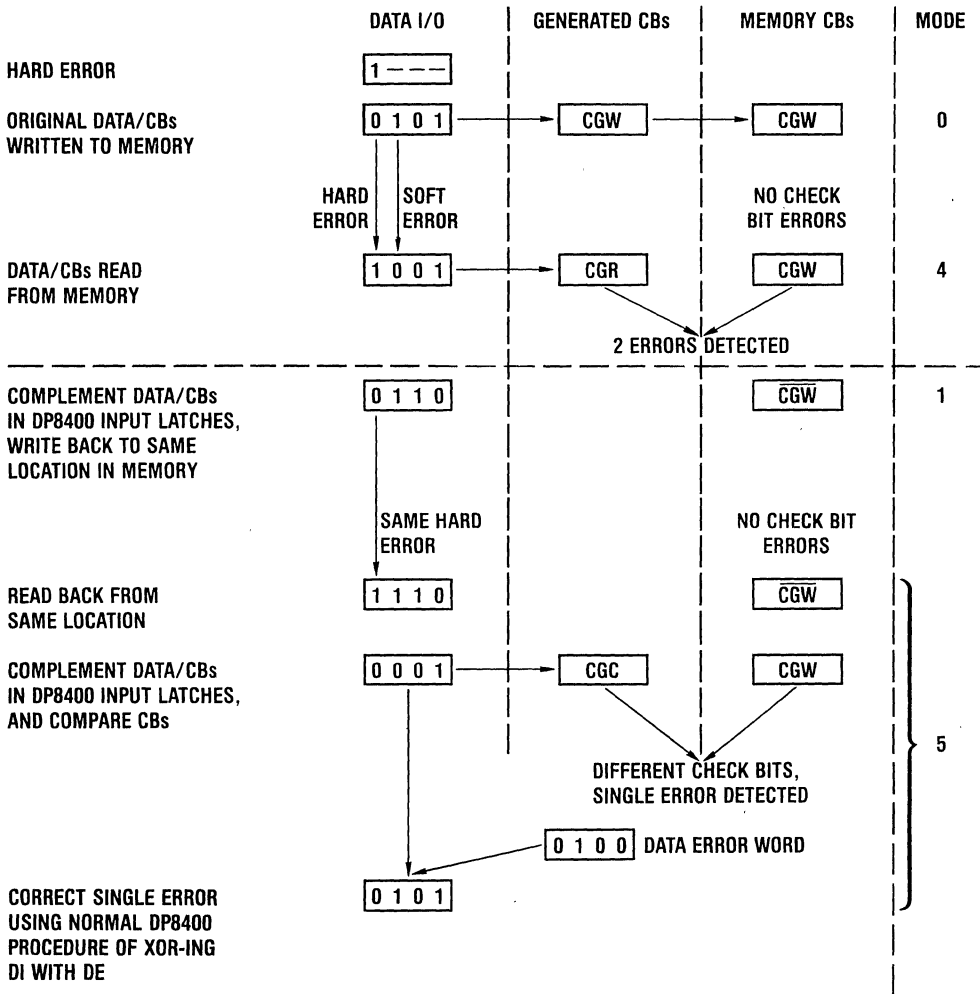


FIGURE 8b. Double Error Correct Complement Hard Error Method — 1 Hard Error, 1 Soft Error In Data Bits

The examples shown in *Figures 8a and 8b* are for 4 data bits. This approach will work for any number of data bits, but for simplicity these examples show how complementing twice corrects two errors in the data bits. The double COMPLEMENT approach also works for any two errors providing at least one is hard. In other words, one data-bit error and one check bit error, or two check bit errors are also corrected if one or both are hard. At the end of the COMPLEMENT READ cycle, the error flags indicate whether the data was correctable or not, as shown in Table XVII. If both the errors were soft, then the data was not correctable and the error flags indicate this.

This approach is ideal where double errors are rare but may occur. To avoid a system crash, a double-error detect now causes the system to enter a subroutine to set the DP8400 in COMPLEMENT mode. This method is also useful in bulk-memory applications, where RAMs are used with known cell failures, and is applicable in 16, 32, 48 or 64-bit configurations. In the 16-bit configuration, modes 1

and 5 of Table III are used. In the 32-bit expanded configuration, modes 1, 5 and 5 are used for the highest chip, and modes 3, 3 and 4 for the lower chip for WRITE, DETECT, and CORRECT. With the lower chip it is necessary to wrap around DOL (after latching its contents in mode 3), back to DIL and perform a Normal READ in mode 4 in the lower chip.

TABLE XVII. ERROR FLAGS AFTER COMPLEMENT READ (MODE 5)

AE	E1	E0	Error Type
0	0	0	Two hard errors
1	1	0	One hard error, one soft check bit error
1	1	1	One hard error, one soft data bit error
1	0	0	Two soft errors, not corrected

Double-Error Correct with Error Logging

Figures 4 and 5 show the E^2C^2 syndrome port connected to an error management unit (EMU). This scheme stores syndromes and the address of locations that fail, thereby logging the errors. Subsequent errors in a memory location that has already stored syndromes in the EMU, can then be removed by injecting the stored syndromes of the first error. To save the addresses and syndromes when power to the EMU is removed, it is necessary to be able to transfer information via the E^2C^2 syndrome port to the processor data bus. This is also useful for logging the errors in the processor. Transfer in the opposite direction is also necessary.

Data Bus to Syndrome Bus Transfer

This is necessary when transferring syndrome information to the error management unit, which is connected to the external syndrome bus. First, data to make $CG = 0$ (all data bits high) must be latched in DIL. Then in mode 2, data is fed to CIL, XOR-ed with 0, and output via SOL with OES low to the syndrome bus. Data is therefore fed directly from the system to the syndrome bus, and this cycle may be repeated as long as DLE is kept low, forcing CG to remain zero.

Syndrome Bus to Data Bus Transfer

This is important when information in the error logger or error management unit has to be read. The DP8400 is set to mode 6B with OES high, and with OB_0 , OB_1 and OLE low. If CSLE is high, the syndrome bus and check bit bus data appear on the lower and upper bytes of the data bus to be read by the system. Also E1 and E0 values that were valid when mode 6 was entered, appear on DQ7 and DQ15.

Full Diagnostic Check of Memory

Using mode 2, it is possible to transfer the upper byte of the data bus directly to the CIL, with CSLE high, without affecting DIL. These simulated check bits then appear on the check bit bus with OLE low, which also causes the previously latched contents of DIL to transfer to DOL. By enabling OB_0 and OB_1 data can be written to memory with the simulated check bits. A Normal READ cycle can then aid the system in determining that the memory bits are functioning correctly, since the processor knows the check bits and data it sent to the E^2C^2 . Another solution is to put the E^2C^2 in mode 6 and read the memory check bits directly back to the processor.

Self-Test of the E^2C^2 On-Card

Again using mode 2, data written from the processor data bus upper byte to CIL may be stored in CIL, by taking CSLE low. Data can now be fed into DIL from the processor, with DLE set high, as in a Normal READ mode (mode 4). Providing CSLE is kept low, the DP8400 will use the simulated check bits in CIL to perform a diagnostic READ, with valid error reporting and correcting. This may be repeated with new data provided CSLE is kept low. In this way memory is not used, thus by reading corrected data in mode 4, and by reading the generated syndromes, and error flags E0 and E1, the DP8400 can be tested completely on-card without involving memory.

Monitoring Generated Syndromes and Memory Check Bits

Mode 6A enables SG0-SG6 onto DQ0-DQ6, and CIL0-CIL6 onto DQ8-DQ14, provided OLE , OB_0 and OB_1 are low. Also the two error flags, E1 and E0 (latched from the previous READ mode), appear on DQ7 and DQ15. This may be used for checking the internal syndromes, for reading the memory check bits, or for diagnostics by checking the latched error flags.

Clearing SIL

In the 16-bit only configuration, or the lower chip of expanded configurations, and in various modes of operation in the higher expanded chips, it is required that SIL be maintained at zero. At power-up initialization, both SIL and DIL are reset to all low. If OES is kept low, SIL will remain reset because CSLE is inhibited to SIL. Another method is to keep OLE always high and the syndrome bus externally set low, or set low whenever CSLE can be used to clear SIL.

Mode 7A also forces the SIL to be cleared whenever CSLE occurs, and also these zero syndromes go to the internal syndrome bus SG. This puts the DP8400 in a PASS-THROUGH mode where the DIL contents pass to DOL and CIL contents to COL, if OLE is low.

Power-Up Initialization of Memory

Both SIL and DIL are reset low at power-up initialization. This facilitates writing all zeroes to the memory data bits to set up the memory. The check bits corresponding to all-zero data will appear on the check bit bus if the DP8400 is set to mode 0 and OLE is set low. All-zero data appears on the data bus when OB_0 and OB_1 are also set low. The system can now write zero-data and corresponding check bits to every memory location.

Byte Writing

Figure 14a shows the block diagram of a 16-bit memory correction system consisting of a DP8400 error correction chip and a DP8409 DRAM controller chip. There are 12 control signals associated with the interface. Six of the signals are standard DP8400 input signals, three are standard DP8409 input signals, and three are buffer control signals. The buffer control signals, PBUF0 and PBUF1, control when data words or bytes from the DP8400/memory data bus are gated to the processor bus and when data words or bytes from the processor are gated to the DP8400/memory data bus.

When the processor is reading or writing bytes to memory, words will always be read or written by the DP8400 and DP8409 error correction and DRAM controller section. The High Byte Enable and Address Data Bit Zero signals from the processor should control the byte transfers via the local bus transceiver signals PBUF0 and PBUF1. The buffer control signal, DOUTB, controls when data from memory is gated onto the DP8400/memory data bus.

Figure 14b shows the timing relationships of the 12 control signals, along with the DP8400/memory data bus and some of the DRAM control signals (RAS and CAS). RGCK is the RAS generator clock of the DP8409 which is used in Mode 1 (Auto Refresh mode), along with being the system clock.

Having two separate byte enable pins, $\overline{OB0}$ and $\overline{OB1}$, it is fairly easy to implement byte writing using the DP8400. First it is necessary to read from the location to which the byte is to be written. To do this the DP8400 is put in normal Read mode (Mode 4), which will detect and correct a single bit error. \overline{WIN} is kept high and \overline{RASIN} is pulled low, causing the DP8400, now in Mode 5 (Auto Access mode), to start a read memory cycle. The data word and check bits from memory are then enabled onto the DP8400/memory data bus by pulling \overline{DOUTB} low. The data and check bits are valid on the bus after the \overline{RASIN} to \overline{CAS} time (t_{RAC}) plus the column access time (t_{CAC}) of the particular memories used. $DLE,CSLE$ can then be pulled low in order to latch the memory data into the input latches of the DP8400. Next \overline{OLE} can be pulled low to enable the corrected memory word, or the original memory word if no error was present, into the data output latches. The corrected memory word will be available at the data output latches " t_{DCD16} " after the memory word was available at the data input latches. Once the corrected data is available at the output latches \overline{OLE} can be pulled high to latch the corrected data. After this $DLE,CSLE$ can be pulled high in order to enable the input data latches again and \overline{DOUTB} can be pulled high to disable the memory data from the DP8400/memory data bus.

There is no reason to use the data or check bit input latches ($DLE,CSLE$) of the DP8400 during the read cycle time period if the memory data and checkbits are valid throughout the cycle.

Now the DP8400 can be put into a write cycle (Mode 0 = $M2 = Low$). At this time the byte to be written to memory and the other byte from memory can be enabled onto the DP8400/memory data bus ($\overline{OB0}$, $\overline{PBUF1}$ or $\overline{OB1}$, $\overline{PBUF0}$ go low). $DLE,CSLE$ can now transition low to latch the new memory word into the data input latch. Next \overline{OLE} is pulled low to enable the output latches. When the new checkbits are valid, t_{DCB16} after the data word is valid on the DP8400/memory data bus, \overline{OLE} and \overline{DLE} can be pulled high to latch the new memory word into the output latches, and then \overline{WIN} can be pulled low to write the data into memory. \overline{RASIN} should be held low long enough to cause the new data and check bits to be stored into memory (\overline{WIN} data hold time).

$DLE,CSLE$ and \overline{OLE} could transition high and low simultaneously instead of being sequenced as was done in this example.

Also a READ-MODIFY-WRITE cycle was performed, taking approximately 30% longer than a normal memory WRITE cycle. A READ and then a WRITE memory cycle could have been used in the above example but it would have taken longer.

Because data from the processor was valid at the same time as data from memory, memory buffers were used ($\overline{PBUF0}, \overline{PBUF1}, \overline{DOUTB}$).

A byte READ from memory is no different from a normal READ. This approach may be used for a 16-bit processor using byte writing, or an 8-bit processor using a 16-bit memory to reduce the memory percentage of check bits, or with memory word sizes greater than two bytes.

Beyond Single-Error Correct

With the advent of larger semiconductor memories, the frequency of the soft errors will increase. Also some memory system designers may prefer to buy less expensive memories with known cell, row or column failures, thus, more hard errors. All this means that double-error correct, triple-error detect capability, and beyond will become increasingly important. The DP8400 can correct two errors, provided one or both are hard errors, with no extra components, using the double complement approach. There are two other approaches to enhance reliability and integrity. One is to use the error management unit to log errors using the syndrome bus, and then to output these syndromes, when required, back to the DP8400.

Double Syndrome Decoding

The other approach takes advantage of the Rotational Syndrome Word Generator matrix. This matrix is an improvement of the Modified Hamming-code, so that if, on a second DP8400, the data bus is shifted or rotated by one bit, and 2 errors occur, the syndromes for this second chip will be different from the first for any 2 bits in error. Both chips together output a unique set of syndromes for any 2 bits in error. This can be decoded to correct any 2-bit error. This is not possible with other Modified Hamming-code matrices.

Absolute Maximum Ratings (Note 1)

Storage Temperature Range	-65°C to +150°C
Supply Voltage, V_{CC}	7V
Input Voltage	5.5V
Output Sink Current	50 mA
Maximum Power Dissipation* at 25°C	
Molded Package	3269mW
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Unit
V_{CC} , Supply Voltage	4.75	5.25	V
T_A , Ambient Temperature	0	70	°C

*Derate molded package 26.2mW/°C above 25°C.

Electrical Characteristics (Note 2) $V_{CC} = 5V \pm 5\%$, $T_A = 0^\circ\text{C}$ to 70°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IL}	Input Low Threshold				0.8	V
V_{IH}	Input High Threshold		2.0			V
V_C	Input Clamp Voltage	$V_{CC} = \text{Min}$, $I_C = -18 \text{ mA}$		-0.8	-1.5	V
I_{IH}	Input High Current	$V_{IN} = 2.7V$		1	160	μA
$I_{IH}(\text{XP})$	Input High Current	$V_{CC} = \text{Max}$, $\text{XP} = 5.25V$		2.5	3.6	mA
$I_{IL}(\text{XP})$	Input Low Current	$V_{CC} = \text{Max}$, $\text{XP} = 0V$		-2.5	-3.6	mA
$I_{IL}(\text{BP0/C7})$	Input Low Current	$V_{CC} = \text{Max}$, $V_{IN} = 0.5V$		-100.0	-500	μA
$I_{IL}(\text{BP1/S7})$	Input Low Current	$V_{CC} = \text{Max}$, $V_{IN} = 0.5V$		-100.0	-500	μA
$I_{IL}(\text{CSLE})$	Input Low Current	$V_{CC} = \text{Max}$, $V_{IN} = 0.5V$		-150.0	-750	μA
$I_{IL}(\text{DLE})$	Input Low Current	$V_{CC} = \text{Max}$, $V_{IN} = 0.5V$		-200.0	-1000	μA
I_{IL}	Input Low Current	$V_{CC} = \text{Max}$, $V_{IN} = 0.5V$		-50.0	-250	μA
I_I	Input High Current (Max)	$V_{IN} = 5.5V$ (Except XP Pin)			1.0	mA
V_{OL}	Output Low Voltage	$I_{OL} = 8 \text{ mA}$ (Except BP0, BP1) $I_{OL} = 4 \text{ mA}$ (BP0, BP1 Only)		0.3 0.3	0.5 0.5	V V
V_{OH}	Output High Voltage	$I_{OH} = -100 \mu\text{A}$ $I_{OH} = -1 \text{ mA}$	2.7 2.4	3.2 3.0		V V
I_{OS}	Output Short Current (Note 3)	$V_{CC} = \text{Max}$		-55	-100	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max}$		340	410	mA
$C_{IN}(\text{I/O})$	Input Capacitance All Bidirectional Pins	Note 4		8.0		pF
C_{IN}	Input Capacitance All Unidirectional Input Pins	Note 4		5.0		pF

Note 1: "Absolute Maximum Ratings" are the values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0V$.

Note 3: Only one output at a time should be shorted.

Note 4: Input capacitance is guaranteed by periodic testing. F test = 10 kHz at 300 mV, $T_A = 25^\circ\text{C}$.

Note 5: All switching parameters measured from 1.5V of input to 1.5V of output. Input pulse amplitude 0V to 3V, $t_r = t_f = 2.5 \text{ ns}$.

DP8400-4 Switching Characteristics (Note 5)
 $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$, $C_L = 50$ pF, unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{DCB16}	Data Input Valid to Check Bit Valid	Figure 9b		35	55	ns
t_{DEV16}	Data Input to Any Error Valid	Figures 10b, 11b		35	45	ns
t_{DCD16}	Data Input Valid to Corrected Data Valid	Figure 10b, $\overline{OB0}$, $\overline{OB1}$ Low		70	85	ns
t_{DSI}	Data Input Set-Up Time Before DLE, CSLE H to L	Figures 10b, 13d		-40	-10	ns
t_{DHI}	Data Input Hold Time After DLE, CSLE H to L	Figures 10b, 13d	16	10		ns
t_{DSO}	Data Input Set-Up Time Before \overline{OLE} L to H	Figure 10b	20	12		ns
t_{DHO}	Data Input Hold Time After \overline{OLE} L to H	Figure 10b	20	12		ns
t_{DE0}	E0 Valid After AE Valid	Figures 9b, 10b, 13d		20	30	ns
t_{DE1}	E1 Valid After AE Valid	Figures 9b, 10b, 13d		12	30	ns
t_{IEV}	DLE, CSLE High to Any Error Flag Valid (Input Data Previously Valid)	Figure 10b		60	80	ns
t_{IEX}	DLE, CSLE High to Any Error Flag Invalid	Figures 9b, 10b		60	77	ns
t_{ILE}	DLE, CSLE High Width to Guarantee Valid Data Latched	DLE	25			ns
		CSLE	50			ns
t_{OLE}	\overline{OLE} Low Width to Guarantee Valid Data Latched	Figure 13d	25			ns
t_{ZH}	High Impedance to Logic 1 from $\overline{OB0}$, $\overline{OB1}$, \overline{OES}	Figures 9b, 10b		32	50	ns
	M2 H to L	Figure 13d		70	85	ns
t_{HZ}	Logic 1 to High Impedance from $\overline{OB0}$, $\overline{OB1}$, \overline{OES} , M2 L to H	Figures 9b, 10b, 13d, $C_L = 15$ pF		25	40	ns
t_{ZL}	High Impedance to Logic 0 from $\overline{OB0}$, $\overline{OB1}$, \overline{OES}	Figures 9b, 10b		30	45	ns
	M2 H to L	Figure 13d		70	85	ns
t_{LZ}	Logic 0 to High Impedance from $\overline{OB0}$, $\overline{OB1}$, \overline{OES} , M2 H to L	Figures 9b, 10b, 13d $C_L = 15$ pF		25	40	ns
t_{PPE}	Byte Parity Input Valid to Parity Error Flags Valid	Figure 9b		40	55	ns
t_{DPE}	Data In Valid to Parity Error Flags Valid	Figures 9b, 13d		60	75	ns
t_{DBP}	Data in Valid to Byte Parity Output Valid	Figure 9b		36	50	ns
t_{MCR}	Mode Change Recognize Time	Figures 9b, 10b		60	100	ns

DP8400-4 Switching Characteristics (Continued) (Note 5)
 $V_{CC} = 5.0V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$, $C_L = 50$ pF, unless otherwise noted.

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{NMR}	New Mode Recognize Time	Figure 10b		60	100	ns
t_{CDV}	Mode Valid to Complement Data Valid	Figure 11b		55	72	ns
t_{CCV}	Mode Valid to Complement Check Bit Valid	Figure 11b		55	72	ns
t_{SCB}	Syndrome Input Valid to Check Bit Valid	Figure 13d		28	41	ns
t_{SEV}	Syndrome Input Valid (CGL) to Any Error Valid	Figure 13d		25	39	ns
t_{SCD}	Syndrome Inputs Valid to Corrected Data Valid	Figure 13d		55	75	ns
t_{DSB}	Data Input Valid to Syndrome Bus Valid	Figure 13d, \overline{OES} Low		45	58	ns
t_{CSB}	Check Bit Inputs Valid to Syndrome Bus Valid	Figure 13d, \overline{OES} Low		40	51	ns
t_{CEV}	Check Bit Inputs Valid (PSH) to Any Error Valid	Figure 13d		35	45	ns
t_{CCD}	Check Bit Input Valid (PSH) to Corrected Data Valid	Figure 13d		70	82	ns
t_{DCB32}	Data Input Valid to Check Bit Valid	Figure 13d		63	96	ns
t_{DEV32}	Data Input Valid to Any Error Valid	Figure 13d		60	94	ns
t_{DCD32}	Data Input Valid to Corrected Data Out	Figure 13d, $\overline{OB0}$, $\overline{OB1}$ Low		125	157	ns

Note 1: "Absolute Maximum Ratings" are the values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: All typical values are for $T_A = 25^\circ C$ and $V_{CC} = 5.0V$.

Note 3: Only one output at a time should be shorted.

Note 4: Input capacitance is guaranteed by periodic testing. F test = 10 kHz at 300 mV, $T_A = 25^\circ C$.

Note 5: All switching parameters measured from 1.5V of input to 1.5V of output. Input pulse amplitude 0V to 3V, $t_r = t_f = 2.5$ ns.

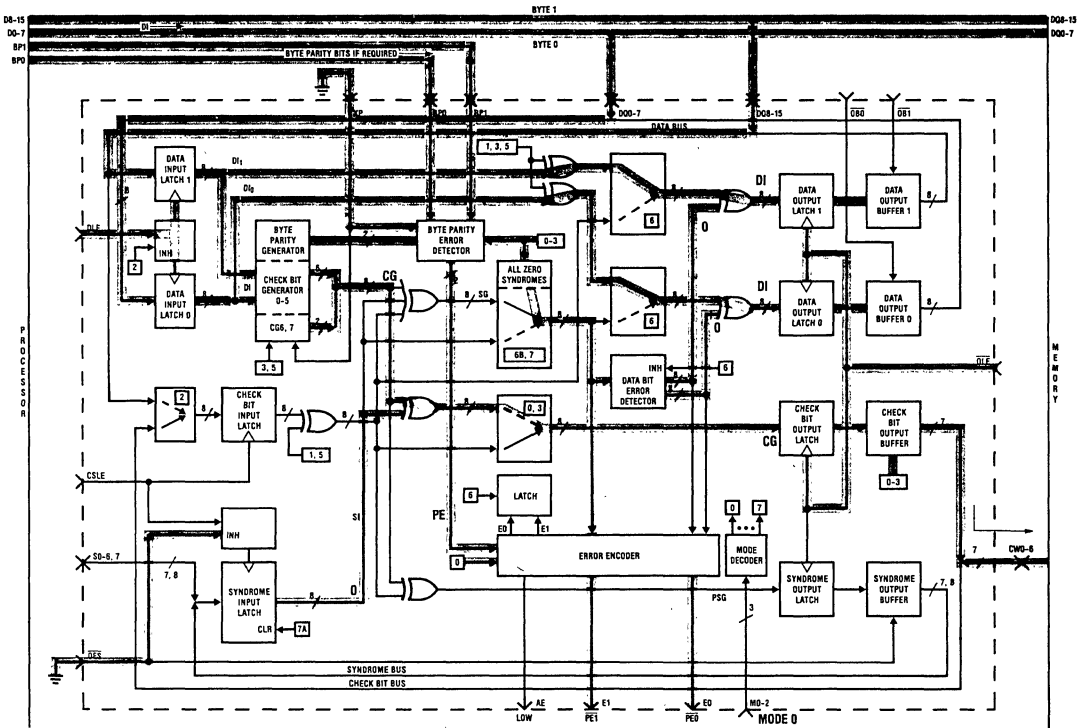


FIGURE 9a. DP8400 16-Bit Configuration, Normal WRITE with Byte Parity Error Detect If Required

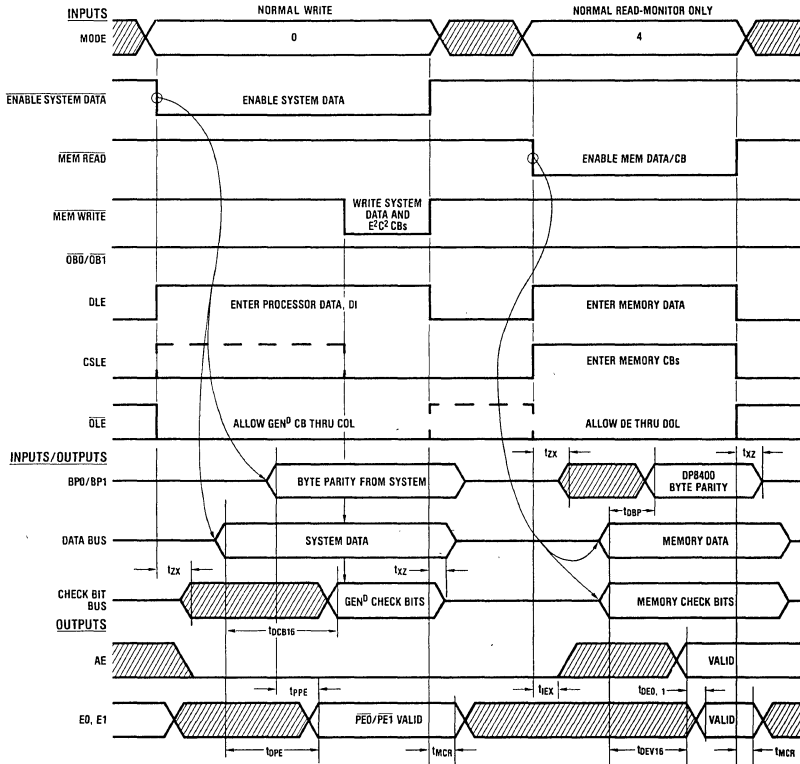


FIGURE 9b. DP8400 16-Bit Configuration, Normal WRITE and Normal READ Timing Diagram

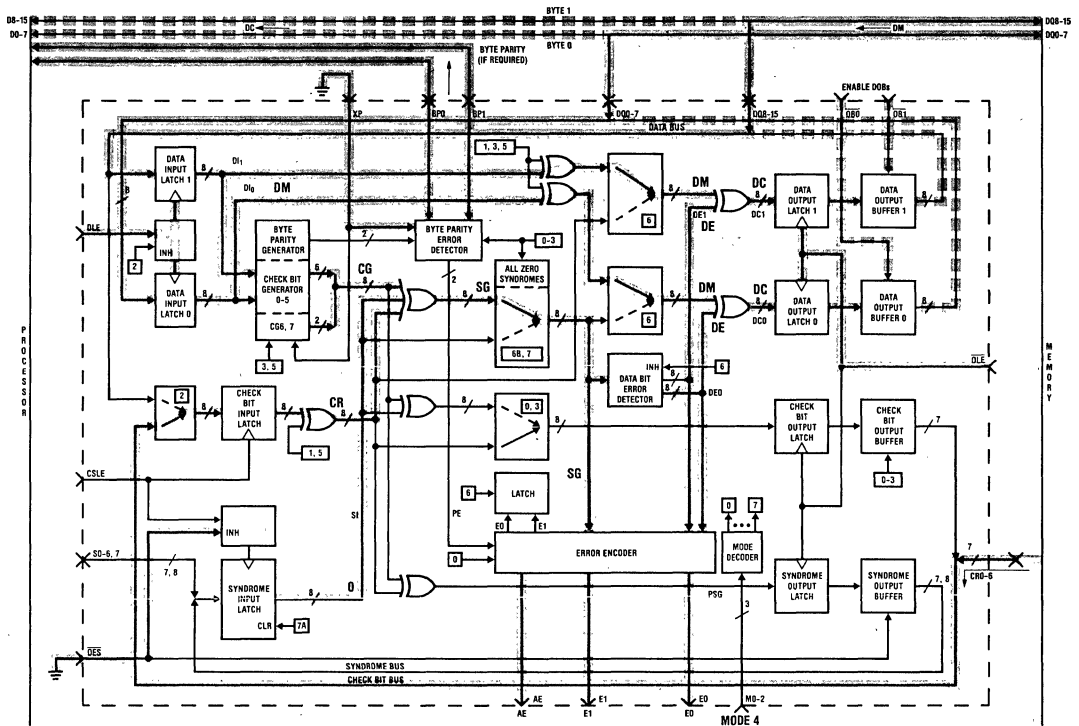
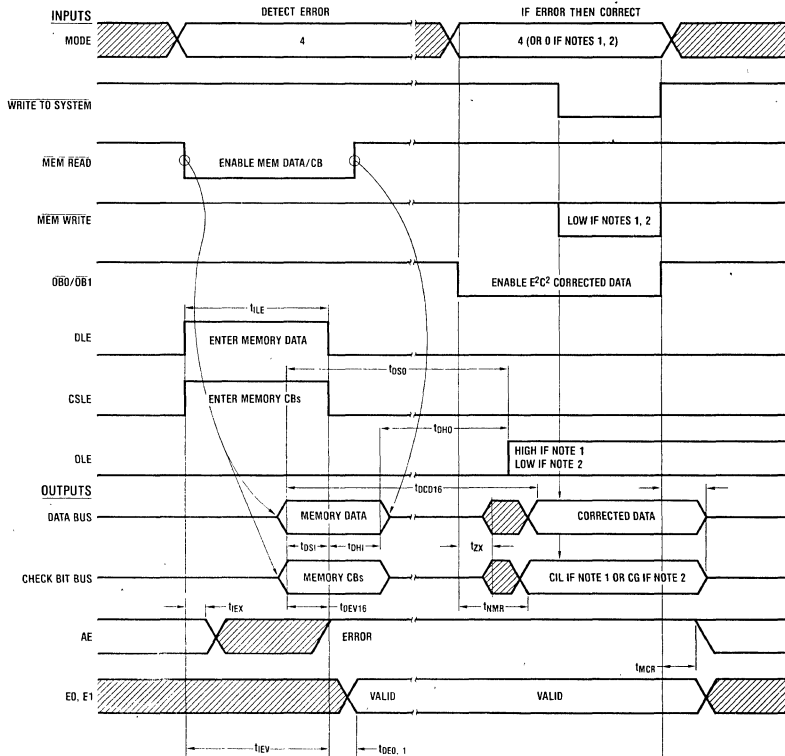


FIGURE 10a. DP8400 16-Bit Configuration, Normal READ — Detect Error (And Correct if Required---)



Note 1: If rewriting correct data and CBs to same location and single data error was detected.

Note 2: If rewriting correct data and CBs to same location and single check bit error was detected.

FIGURE 10b. DP8400 16-Bit Configuration, DETECT THEN CORRECT Timing Diagram

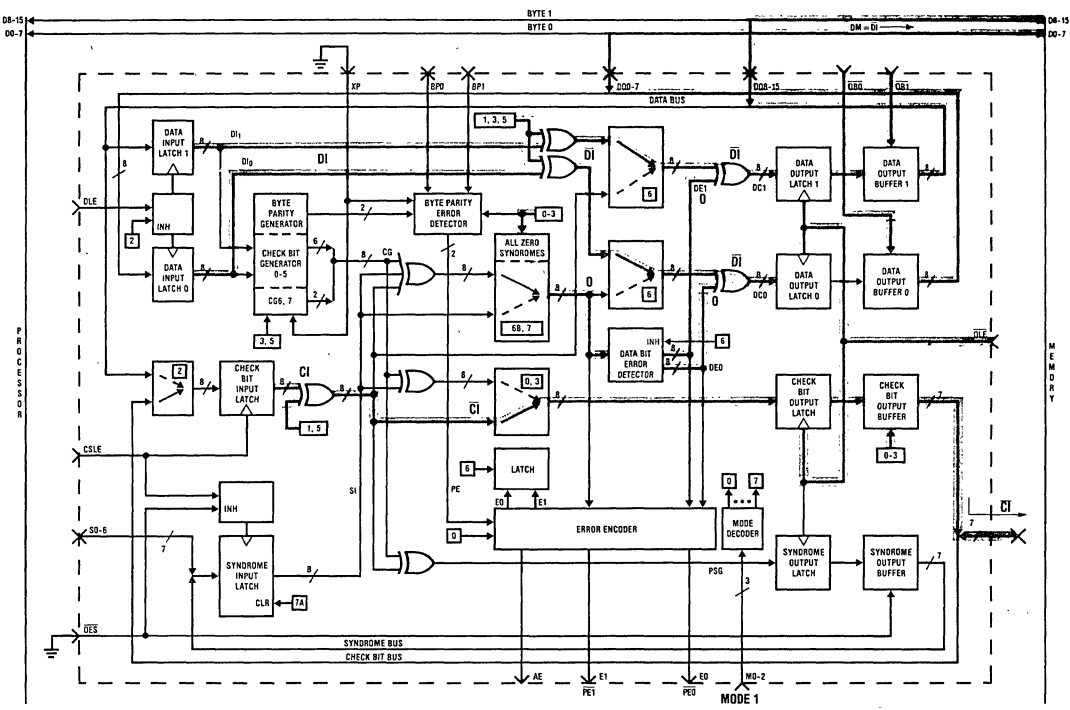
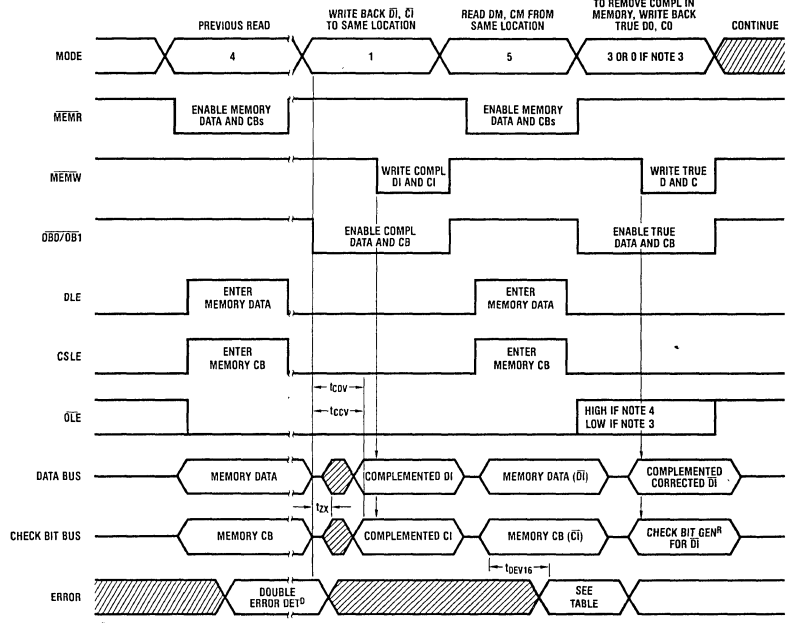


FIGURE 11a. DP8400 16-Bit Configuration, COMPLEMENT WRITE



Note 3: If rewriting corrected data and CBs back to same location and 1 soft data bit error was detected.
Note 4: If rewriting corrected data and CBs back to same location and 2 hard errors or 1 soft check bit was detected.

FIGURE 11b. DP8400 16-Bit Configuration, Detect 2 Errors, COMPLEMENT WRITE, COMPLEMENT READ, Output Corrected Data Timing Diagram

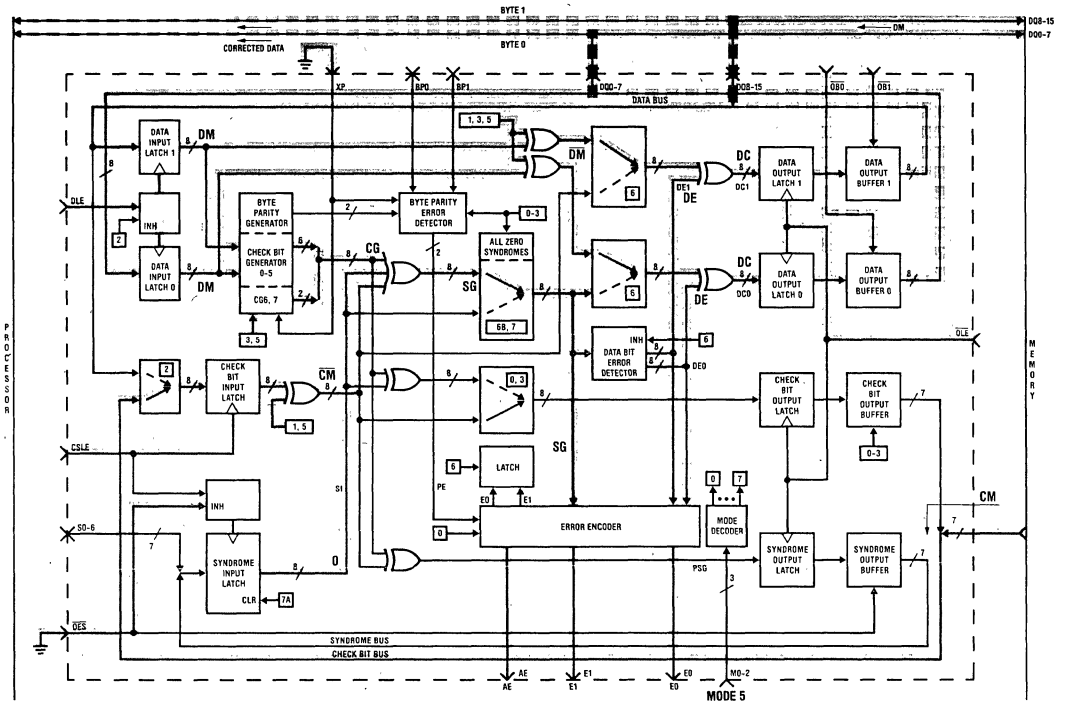


FIGURE 11c. DP8400 16-Bit Configuration, COMPLEMENT READ and Output Corrected if One or Two Hard Errors (---)

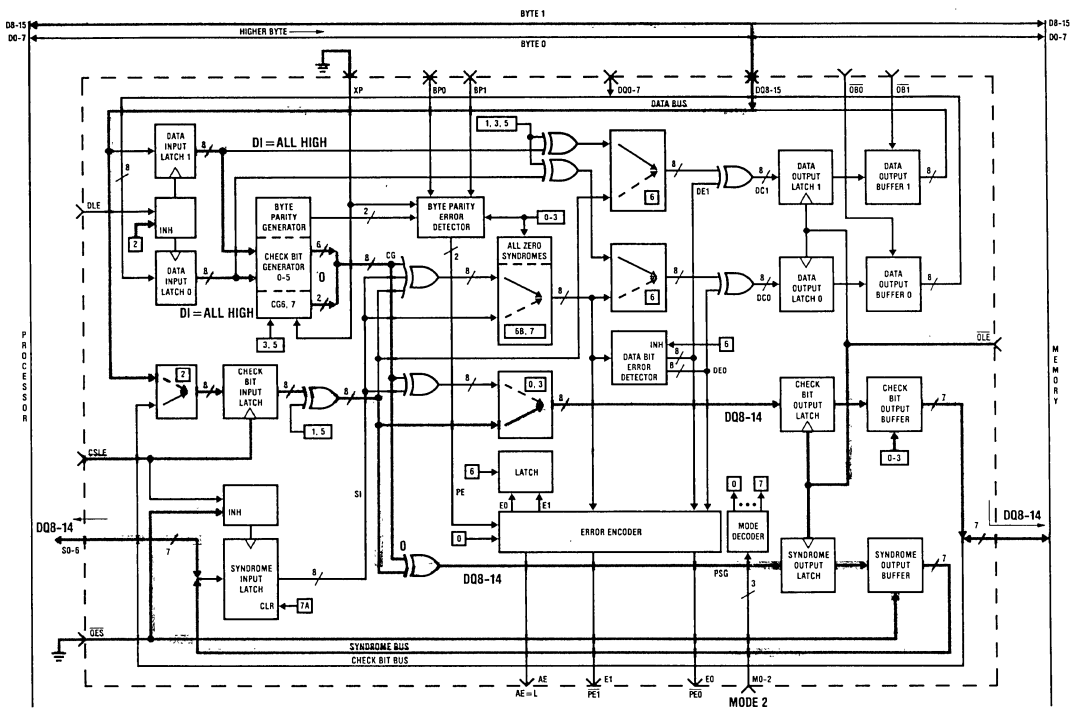


FIGURE 12a. DP8400 16-Bit Configuration, Diagnostic WRITE, READ. Data Bus to Check Bit Bus or Syndrome Bus (Providing DI = HIGH in Previous Cycle to Set CG = All Zero For Transfer to S).

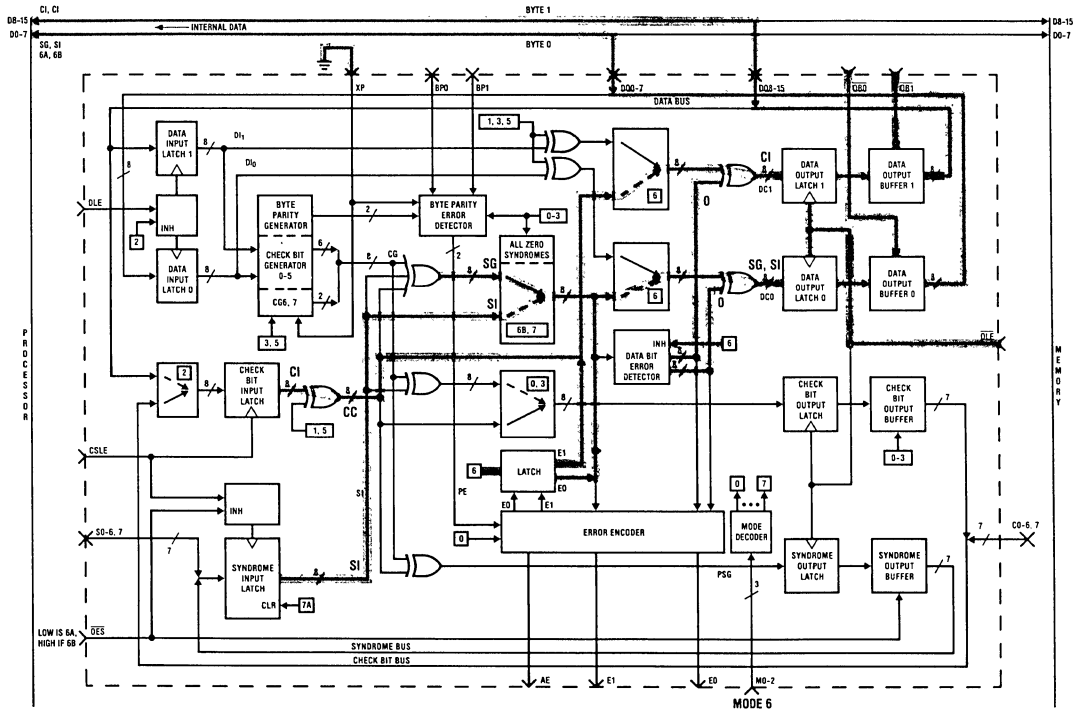
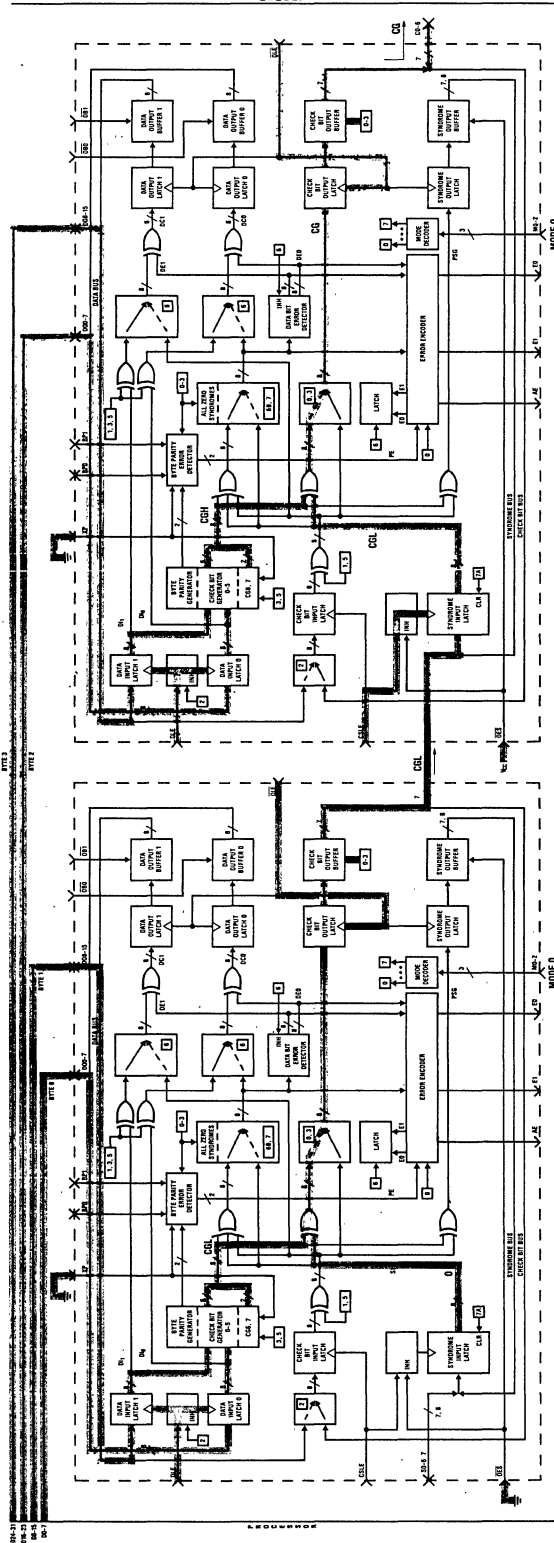


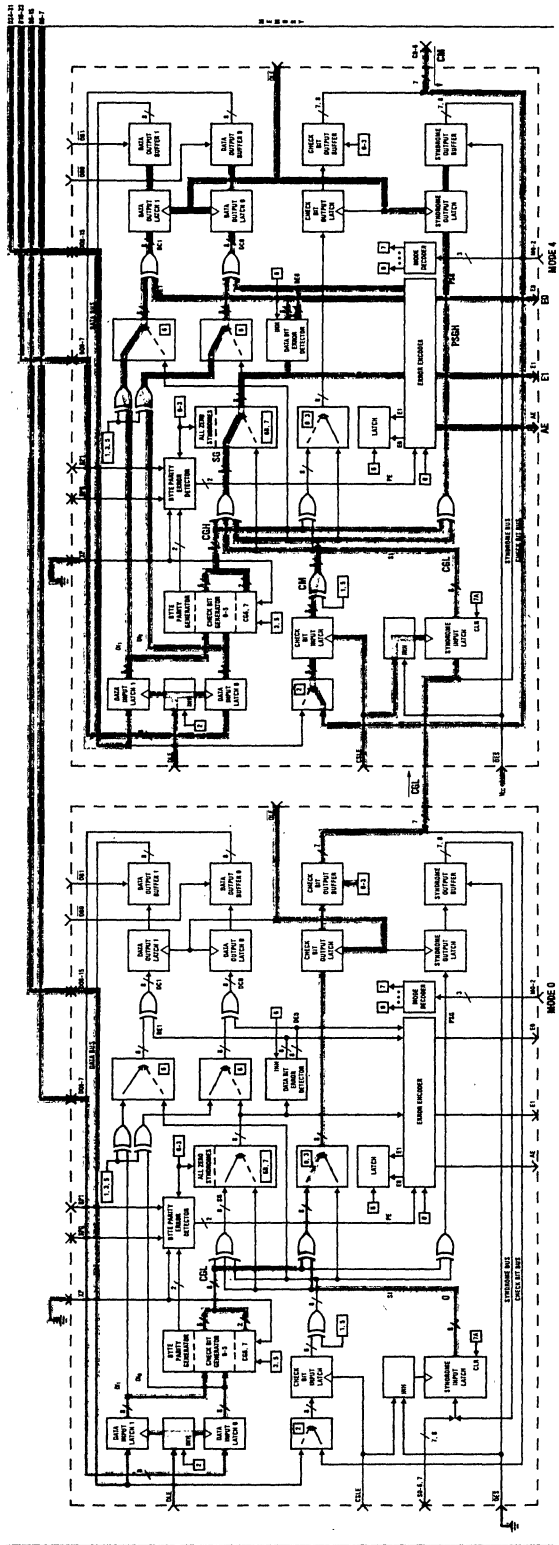
FIGURE 12b. DP8400 16-Bit Configuration, Monitor on Data Bus — Memory Check Bits



DP8400 (H)

DP8400 (L)

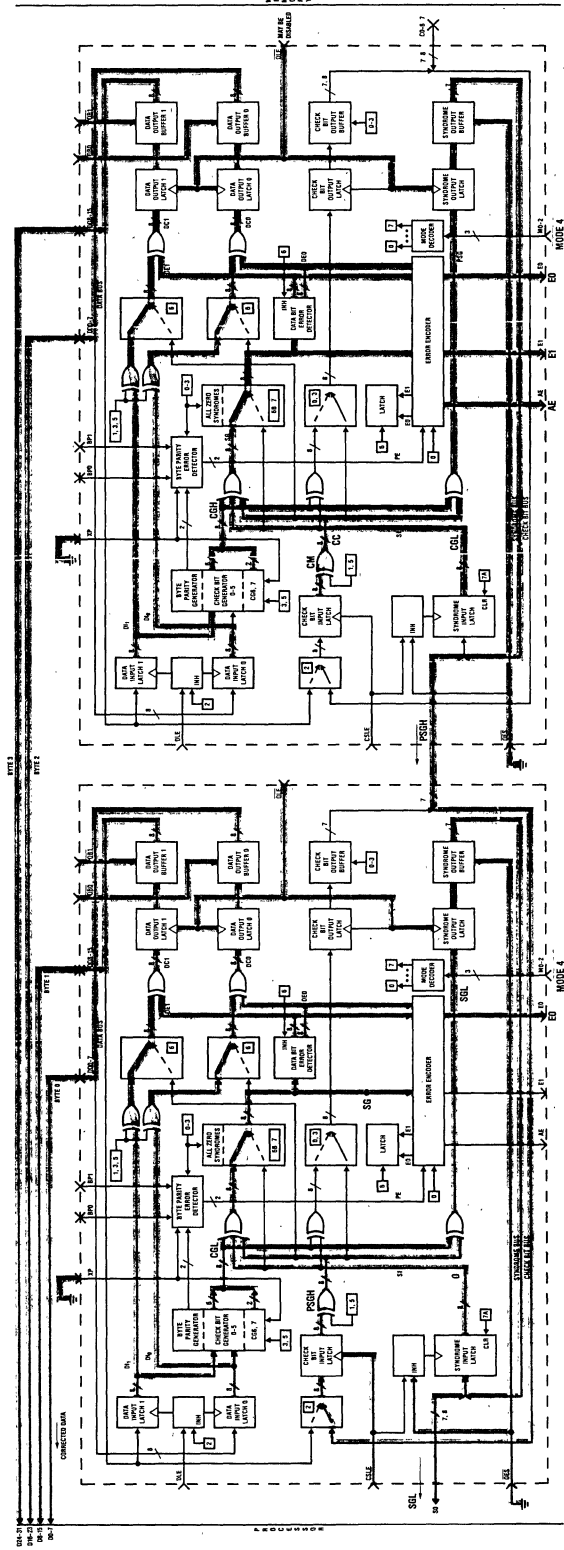
FIGURE 13a. DP8400 32-Bit Configuration, WRITE



DP8400 (H)

DP8400 (L)

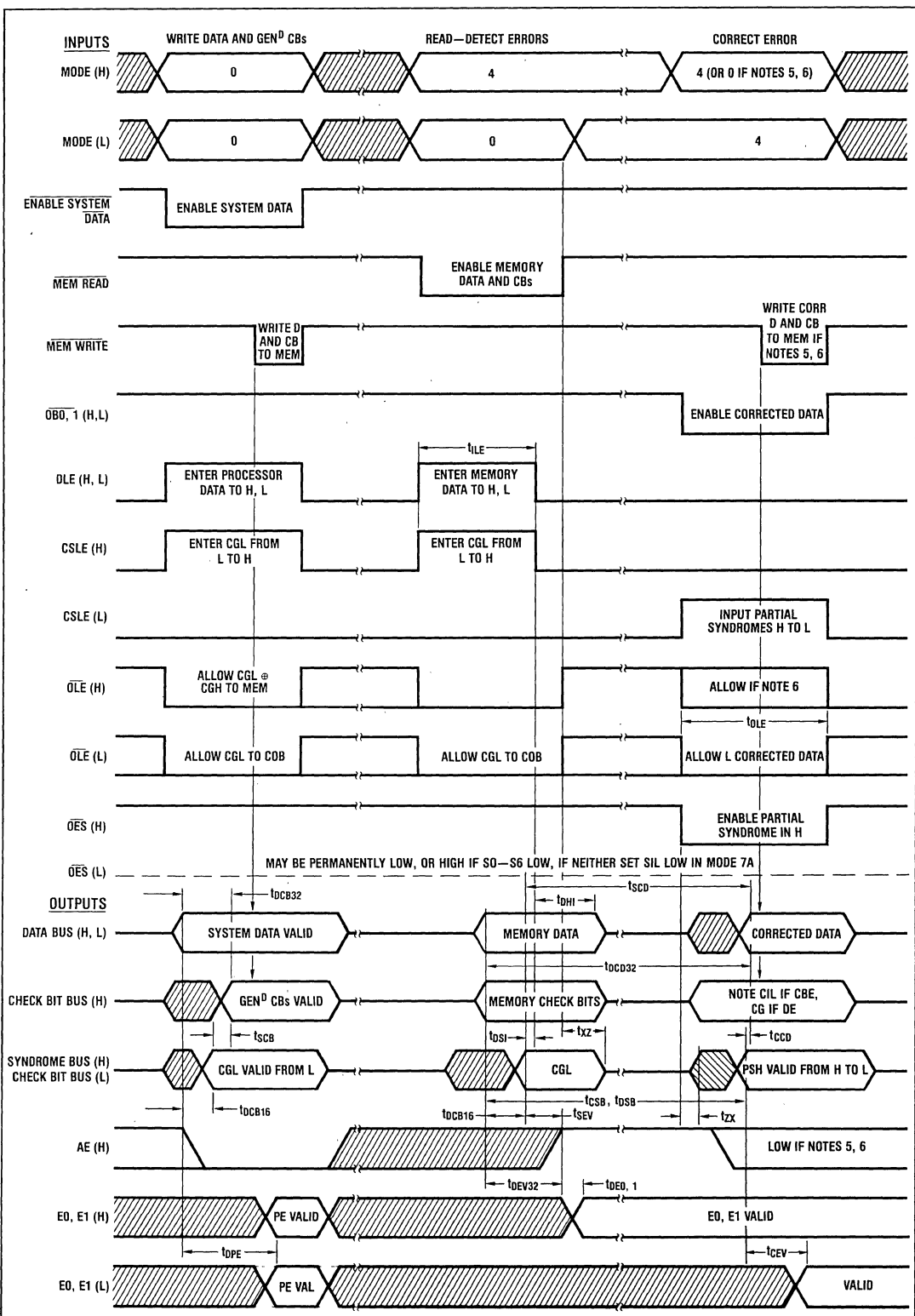
FIGURE 13b. DP8400 32-Bit Configuration, READ Detect Error Only



DP8400 (H)

DP8400 (L)

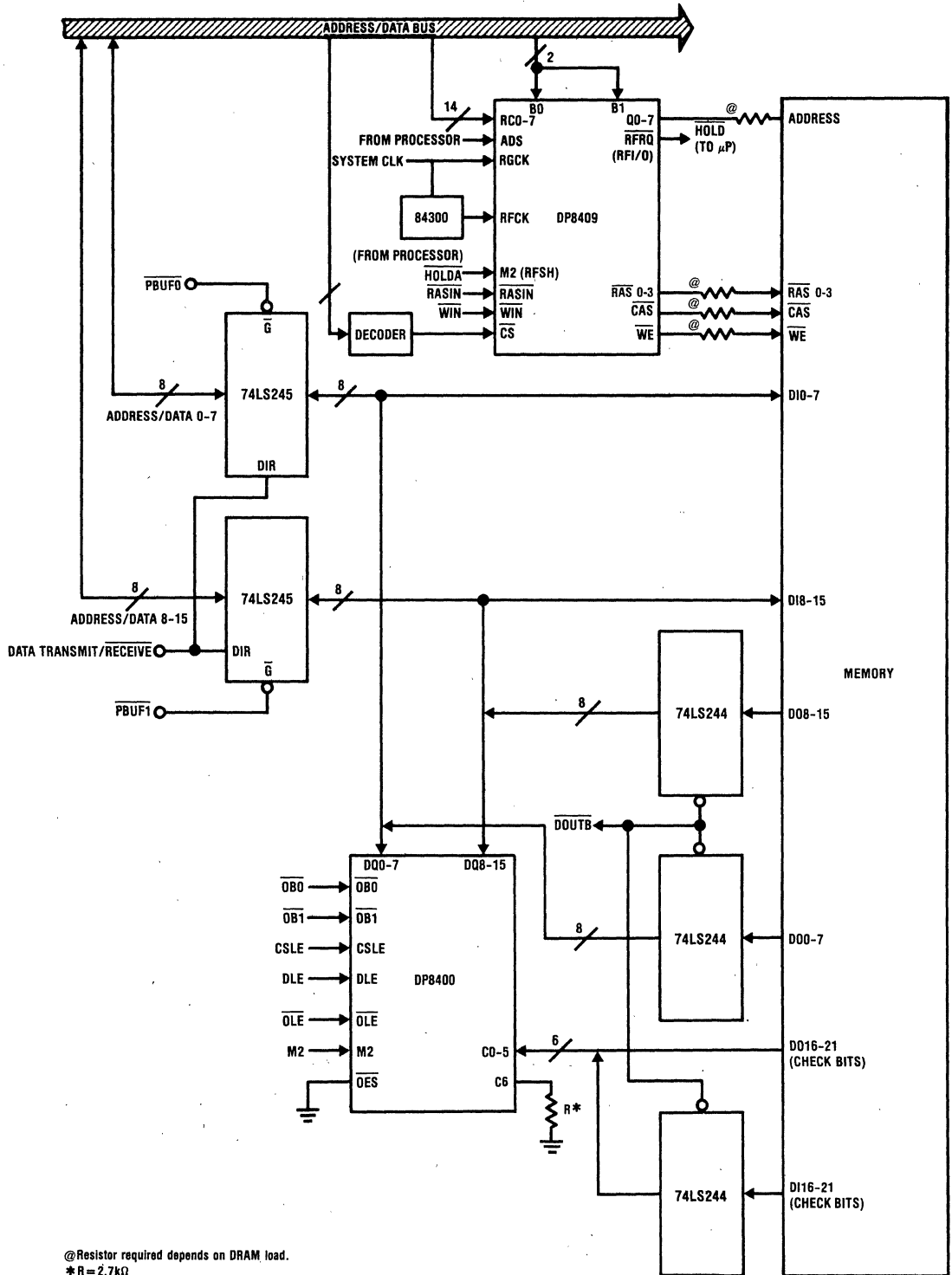
FIGURE 13c. DP8400 32-Bit Configuration, READ Correct Data



Note 5: If rewriting corrected data and CBs back to same location and single data error was detected.

Note 6: If rewriting corrected data and CBs back to same location and single check bit error was detected.

FIGURE 13d. DP8400 32-Bit Configuration, WRITE, DETECT and CORRECT Timing Diagram



@Resistor required depends on DRAM load.
 *R = 2.7k Ω

FIGURE 14a. DP8400/8409 System Interface Block Diagram (See Figure 14b for Byte Write Control Timing)

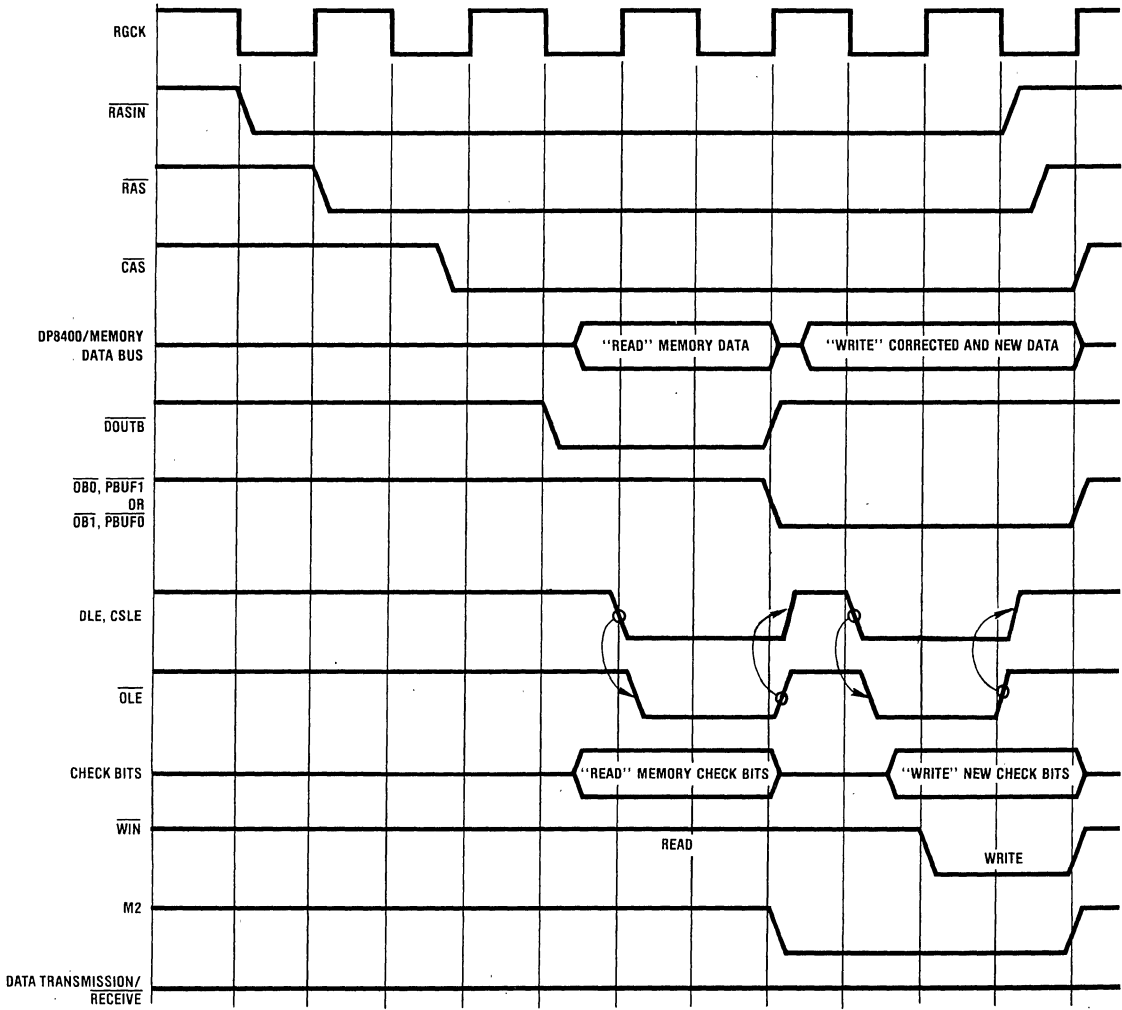


FIGURE 14b. DP8400 16-Bit Configuration, Byte Write Timing

Expanding the Versatility of the DP8400

National Semiconductor
Application Note AN-306
June 1982
Mike Evans



Basic Operation of the DP8400

Introducing error correction capabilities to a memory incurs some penalties—extra memory, additional access times, and extra control circuitry. The DP8400 has been designed to minimize the last two, and for some data word widths, less extra memory is required than for other error correction circuits.

In systems using error correction, extra memory is needed for check bits, which are merely parity bits, each derived from different combinations of the data bits. If a single error does occur, the error correction circuit can determine which bit is in error and then complement that bit, to re-create the original data word. As the memory data word widens, the ratio of check bits to memory data bits is reduced. As a rough guide, starting with four data bits and four check bits, one additional check bit is required each time the data word doubles.

A circuit diagram of how the DP8400 generates the check bits in a write cycle and corrects errors in a read cycle is shown in *Figure 1a*, which uses four data bits and four check bits. A 4-bit example is shown in *Figure 1b*. In a write cycle, the data input latch, DIL, receives the system data and generates four parity bits or check bits, which pass through the check bit output latch, COL, and buffer, to be written to the selected memory location. This delays every write cycle, but fortunately the DP8400 takes only 30 ns extra to generate the (six) check bits. When this location is subsequently read, the four memory data bits pass through DIL to generate four new checks bits. The four memory check bits pass through the check bit input latch, CIL, and are

fed into four Exclusive-OR gates with the four generated check bits. The outputs of these gates are called syndrome bits, and obviously, if there are no errors, the two sets of check bits will be the same and no syndrome bits will go high. If there is an error in the check bits, only the corresponding syndrome bit will go high; in this case the data bits are still correct. If one of the data bits is in error, three syndrome bits will go high (in the case of DP8400, three or five will go high), and the syndrome word is unique for any of the bits in error. The four AND-gates decode which bit is in error and complement it out of the second set of Exclusive-OR gates. The other three output bits remain the same as the input bits, so the corrected word is now available to the system.

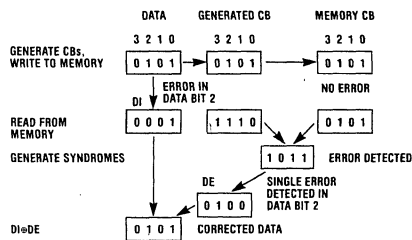


Figure 1b. Example of Single Error Correction

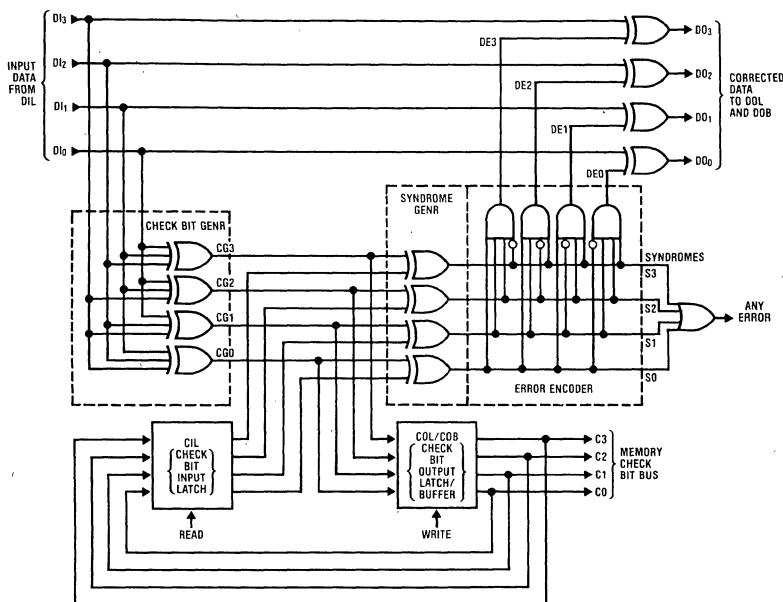


Figure 1a. Error Correction 4-Bit Functional Diagram

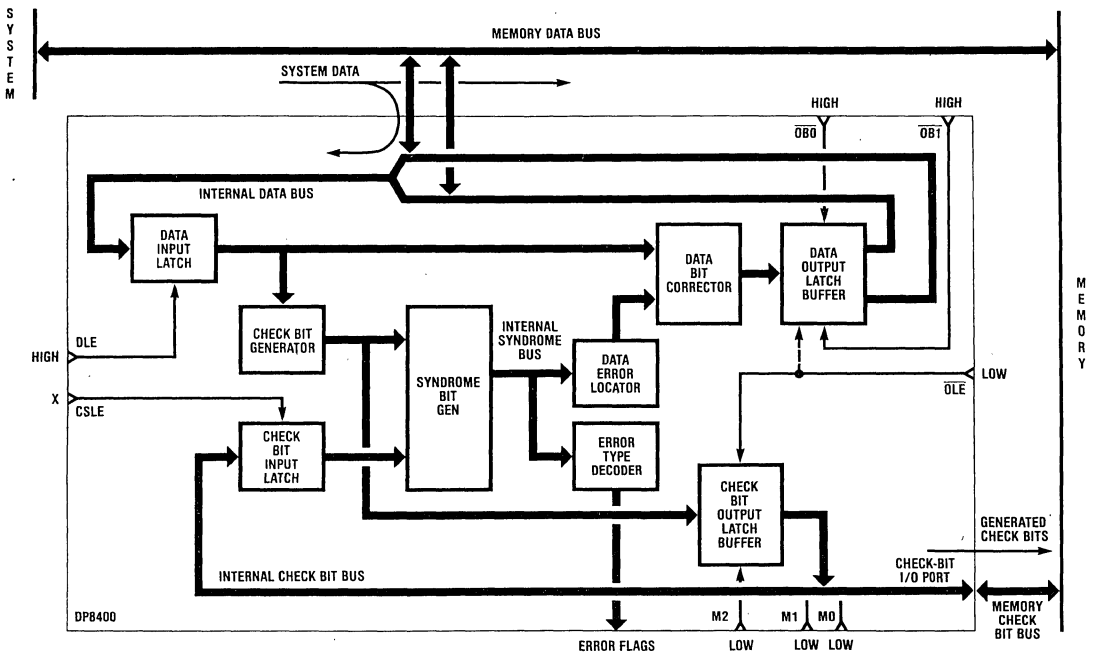


Figure 2a. DP8400 Read From Memory Cycle

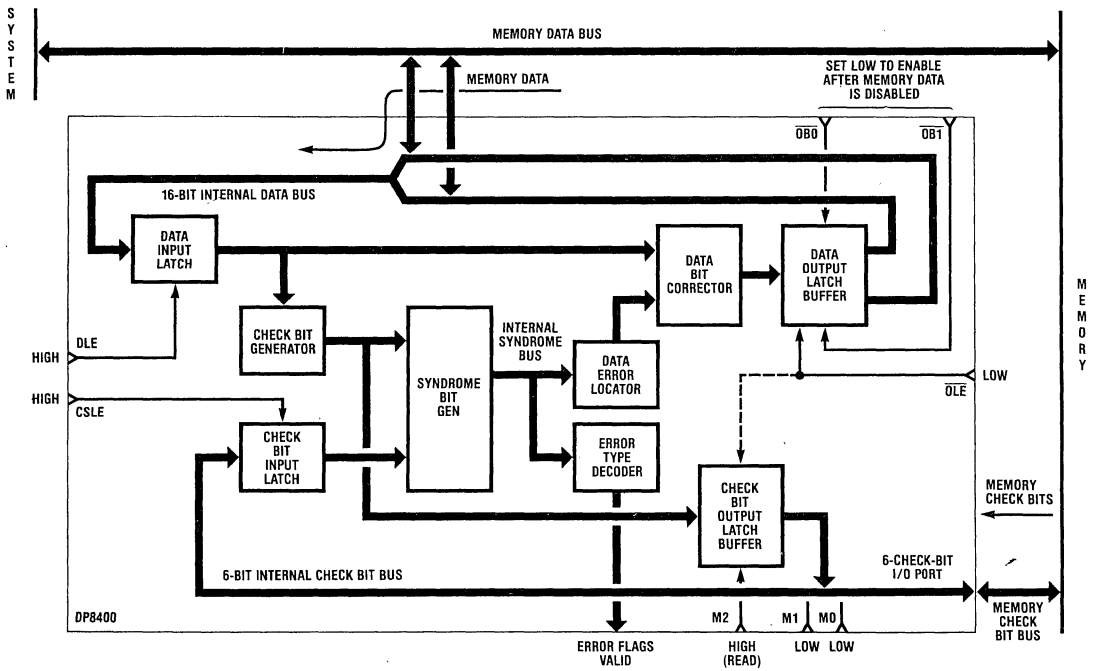


Figure 2a. DP8400 Write to Memory Cycle

In the case of the DP8400 with 16 data bits and 6 check bits, there are 16 AND-gates to decode the 6 syndrome bits to determine the data bit in error. Table 1 shows the DP8400 matrix, called a Nelson Code, which has some unique features concerned with double soft error correction. For the purposes of this description, the matrix may be considered to be a form of Modified Hamming Code. The matrix has two functions: horizontally it tells us the value of the generated check bits for any data word when writing to memory, and vertically it tells us the syndrome word for any data bit in error. In a write cycle to memory, a '1' in any row indicates that the data bit in that column helps generate the parity bit in that row. For example, check bit 1 checks the parity of data bits 3, 6, 8, 9, 11, 13, 14 and 15, and generates even parity for those data bits. In a read cycle from memory, three or five of the six syndrome bits will go high for a single data bit error, and the columns represent the syndrome word, so the data bit in error is the number at the top of the column for that syndrome word. The 16 AND-gates each decode one of the 16 syndrome words shown in the columns of Table 1, to locate the error. If there is a data bit error, one of the outputs of the 16 AND-gates will go high, to complement the data bit in error.

If two errors have occurred, the syndrome word is simply the Exclusive-OR of the syndrome words of the two individual bits in error, whether data or check bits, and is always even parity. First, if two check bits are in error, the corresponding two syndrome bits will go high. Second, for one data bit and one check bit error, then either two, four or six syndrome bits will go high. Finally, if two data bits are in error, again two, four or six syndrome bits go high. Thus a parity check on the syndromes will indicate any two errors. This is important because if we know there are two errors, the DP8400 can attempt to correct them. The third error flag, E1, is the parity of the syndrome bus and check bit error. The DP8400 provides three error flags AE (Any Error), E0 and E1, as shown in Table 2, so that the exact nature of the error can be determined.

Configuration and Control of the DP8400

The DP8400 has a 16-bit data I/O port and an 8-bit check bit I/O port (6 bits used with 16 data bits) for applications with memories used with 16-bit microprocessors. The 16-bit data I/O port sits on the memory data bus, and the 6 check bit I/O port connects directly to the check bit section of memory. In other words, each memory location now contains 16 data bits with 6 check bits. The DP8400 is expandable to beyond 80 data bits, each additional 16 data bits requiring an additional DP8400 without the need for extra logic circuitry. 32-bit wide memory busses are also a popular width for minicomputers. In addition, 16-bit microprocessor systems may use 32-bit memory, because this larger memory data width requires only 7 check bits, a lower percentage overhead of check bits to data bits.

Figures 2a and 2b show a simplified block diagram of the DP8400 with its control signals. The numerous control signals provide ease of use in the many varied applications of this chip. There are three latch enable signals DLE, CSLE and OLE. Whenever DLE is high, data on the data I/O port D0-15 is entered into the data input latch DIL, and is latched in as DLE goes low. This allows either processor or memory data to be present on the

data bus for only 3ns prior to, and held over for 10ns after DLE goes low. The data can then be removed if desired. Similarly, CSLE, when high, allows check bits on the check bit I/O port and external data on the syndrome I/O port to enter the check bit and syndrome input latches (CIL and SIL), respectively. These are latched in as CSLE goes low. (In 16-bit operation, OES, Output Enable Syndromes, will be set low permanently, inhibiting CSLE to SIL, which remains in the power-up reset condition so that it does not affect the simplified block diagram.) OLE, when set low, allows internal information into the data and check bit output latches (and the syndrome output latch, not shown). As OLE goes high, this information becomes latched. For some less complex designs, DLE, CSLE and OLE may be linked together. Providing OLE was low to allow corrected data into DOL, then OB0 and OB1, when set low, enable the two data output buffers to present corrected data to the system. Data is enabled or disabled within 15ns of these inputs going low or high, respectively.

The DP8400 has three mode pins, M2, M1 and M0, which offer eight major modes of operation, designated 0 to 7. The most important two are Normal Write and Normal Read, and for these M1 and M0 are set low. M2 is READ/WRITE so Normal Write is mode 0 and Normal Read is mode 4. Other modes are used for the Double Complement Correct approach (Modes 1, 3 and 5) and for diagnostics (Modes 2 and 6). Mode 7 is used when expanded to more than 16 data bits and fast correction times are required.

Normal Operation With a 16 Data Bit Memory

The basic requirements for normal operation of the DP8400 are that it generate check bits, detect errors and correct them with minimum delays, and that it be easy to use. In normal operation M1 and M0 are set low. Figure 2a shows how the DP8400 generates check bits when writing data to memory. DLE may be kept high, OLE low, CSLE low, and M2 low so that the DP8400 is in Mode 0. System data is presented to the data I/O port on pins D0-15, and enters DIL, where it connects to the check bit generator CG. The six generated check bits pass through COL and are enabled (with M2 low) onto the check bit I/O port. The six generated check bits will appear 30ns after the 16 data bits are presented to the data I/O port. A write to memory will now store the 16 data bits and 6 corresponding check bits in the selected location of memory. The write cycle is therefore slowed down by 30ns, which in most memory systems is not significant.

Figure 2b shows the paths when reading from memory, with DLE set high to enter the memory data bits into DIL, and CSLE also set high to enter memory check bits into CIL. M2 is set high so that the DP8400 is in Mode 4. The Any Error flag, AE, becomes valid 35ns after memory data and check bits are valid. Error flags E1 and E0 become valid approximately 15ns later. Thus, if AE is low, no further operations are necessary. For fast 16-bit microprocessor systems, it may be necessary to introduce a wait state every read cycle to first determine if an error exists. If no error is detected the wait state is removed and the read cycle continues.

If an error is detected, then the error flags E1 and E0 must be examined to determine the required action. If

the error is a single data bit error, DOL will by now contain corrected data. If there is no check bit error, then COL, which follows CIL when in Mode 4, now contains the original check bits. By taking \overline{OLE} high, corrected data bits are latched in DOL, and correct check bits in COL. The memory is now disabled, so that $\overline{OB0}$ and $\overline{OB1}$ can be set low to enable corrected data onto the data bus, and M2 set low to enable the contents of COL onto the check bit bus. A write to the same location of memory will therefore remove the data bit error if it was a soft error. The microprocessor can read the corrected data once the wait signal is removed.

If the error is a single check bit error, DLE should be set low. DOL contains the contents of DIL, still correct data. Memory can now be disabled so that $\overline{OB0}$ and $\overline{OB1}$, when set low, output correct data, and M2 when set low, allows the generated check bits from DIL to be output on the check bit I/O port. A write to the same location of memory will remove the check bit error if it was a soft error. The microprocessor now reads this correct data when the wait signal is removed. If a double bit error is detected, then other approaches may be taken, as described in the data sheet and later in this application note.

The primary features of the DP8400 are discussed in the data sheet; there are, however, a number of other features that become very useful once a designer becomes acquainted with error correcting techniques.

These include: expansion beyond 16 data bits, diagnostic routines, error logging (allowing some double error correction), and a novel approach offering fast correction of any double error. This application note discusses how the DP8400 has been designed to function in all of these applications, making it the most versatile and comprehensive error correction chip available.

Error Checking and Correcting for Wider-Than-16-Bits Data Widths

At present, most 16-bit microprocessor systems use a 16-bit wide main memory, partly for simplicity, and also because main memories, in general, have not become large enough in size to justify otherwise. The data sheet shows how to accomplish this with one DP8400, utilizing the matrix of Table 1. It is fairly easy to use a memory of twice the microprocessor data width to reduce total chip count when incorporating error correction capability. One example would be a complex 8-bit microprocessor using large main memory. If the memory data width is kept at eight bits, then five check bits are required for error correction for each byte of data. If four banks of memory are required, each bank comprising 13 chips, then 52 total memory chips are required and only 62% of the memory is used for system data. If the memory data width is increased to 16 bits for the same microprocessor-based system, then six check bits are required.

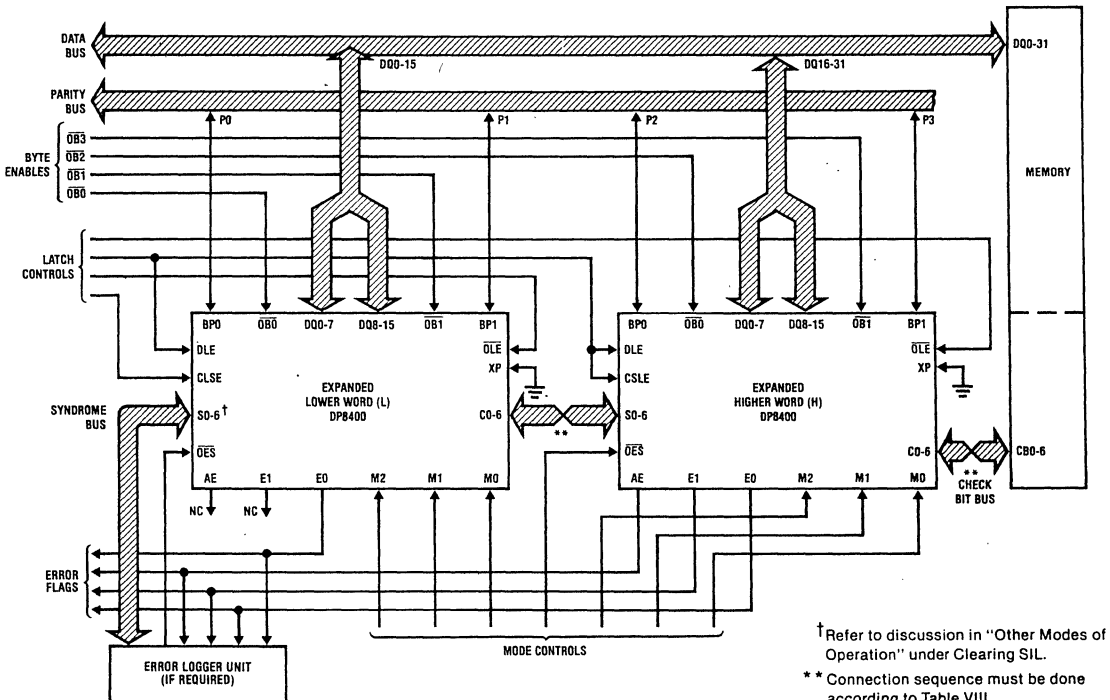


Figure 3. 32-Bit Error Detection and Correction

† Refer to discussion in "Other Modes of Operation" under Clearing SIL.

** Connection sequence must be done according to Table VIII.

The memory now comprises two banks each of 22 chips, totaling 44 memory chips—a savings of eight memory chips. This saving is offset somewhat by the need to incorporate byte-writing capability, which does require extra components and slows down the memory write cycle. One DP8400 is still needed, using all 16 bits, and two bidirectional buffers are also required.

As a second example, using a 16-bit microprocessor with a memory of eight banks, each comprising 16 bits of data and six check bits, the total is 8×22 or 176 memory chips. Once the memory is widened to 32 data bits with seven check bits, only four banks are required, and the total number of memory chips reduces to 4×39 , or 156—a savings of 20 memory chips. This is offset a little by the fact that an extra DP8400 is required, and slightly slower memory write and read cycles are necessary. In some cases, therefore, widening the memory data bus becomes more practical for larger memories.

Saving memory chips is just one reason why there is a need to be able to expand the DP8400 beyond 16 data bits. Most minicomputers now use 32-bit wide data busses, and soon there will be some 32-bit microprocessors. Other systems use 24 bits, 48 bits, 52 bits, 64 bits or a variety of other data widths. The DP8400 has been configured to be expandable to any data width, even beyond 80 bits, merely by inserting an additional DP8400 for each 16-bit increment in memory data.

A section of the chip shown in the data sheet Block Diagram comprises the syndrome input and output latches, SIL and SOL, and a dedicated syndrome I/O port. This port has a number of uses not normally needed in simple 16-bit single error correction applications.

One use of this syndrome port is for data widths wider than 16 bits. Only one DP8400 is required with 16 data bits or less, but if a system uses more than 16 memory data bits, additional DP8400s are required. For example, two DP8400s, one with its 16-bit data port connected to the lower word, and the other to the higher word, can be configured to generate check bits, and detect and correct errors for a 32-bit memory as shown in Figure 3. For writing to memory, both chips will still generate six check bits from the two words of 16 bits. But with more than 26 total data bits, seven check bits are required. Therefore, it is necessary to combine the two sets of check bits to produce seven composite check bits to be written to memory as shown in the flow path depicted in Figure 4a. This is achieved by outputting the six generated check bits from the lower word DP8400 (designated L), and inputting them to H, the higher word DP8400. The syndrome port of H is available to receive these check bits from L, to be loaded into SIL of H, provided CSLE is high. The six outputs from SIL combine with the six check bits generated in H to create seven composite check bits, and this 7-bit combination is output on the check bit port to the memory check bits. Table 2 shows one of twelve possible ways to combine the two sets of check bits. Note that the lower word matrix for bits 0 and 15 is identical to Table 1 with the addition of all "0"s for the seventh check bit. The higher word matrix for bits 16 to 31 uses the same rows but in a different order, implying that the check bits from L must be cross-connected to H. For example, memory check bit 5 is generated from check bit 1 of L and check bit 5 of H. Both chips are therefore set to normal write mode when generating check bits.

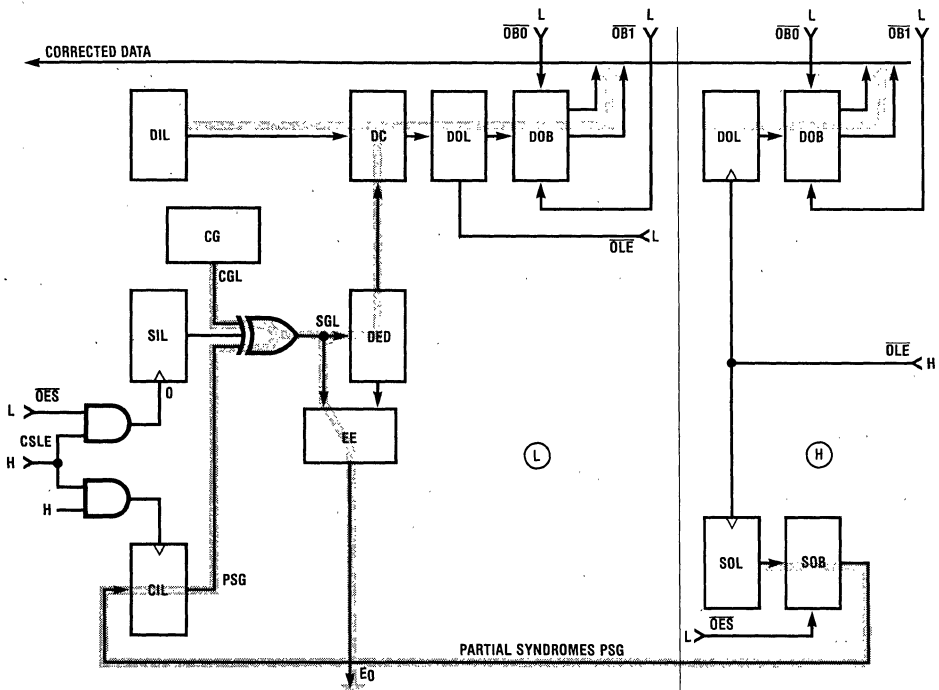


Figure 4a. E²C² 32-Bit Configuration, Error-Correct Flow Path

When reading from memory, the two chips first need to detect for an error. Figure 4b shows the flow path through the chips. L is set to normal write mode and H to normal read mode. Memory data is supplied to both chips so that L generates six check bits from the lower word data bits, and feeds them to SIL of H, the same as for writing. H also generates its own check bits which combine with those from L, and these seven composite check bits are compared with the seven memory check bits fed into CIL of H. This combining, plus comparison of check bits, is equivalent to seven 3-input Exclusive-OR gates. The output of these Exclusive-OR gates are the seven syndrome bits, and these can be decoded to determine the type of error. First, if there is no error, error flag AE of H will remain inactive because memory data is correct, provided \overline{OLE} is kept low, and DOL of both L and H will contain correct data. Second, if there is a memory check bit error, only one of the seven syndromes will go high and the three error flags of H will indicate a check bit error as in Table 3. Note that memory data is still correct, and with \overline{OLE} low, DOL of both L and H contain correct data. Third, if there is a single data error in bits 16-31, the syndromes of H are such that the data error locator will locate the error and correct it, so again DOL of both L and H contain correct data. This is because the seventh syndrome bit is low for an error in the higher word, so that we have a six syndrome bit word as in Table 1, to be decoded as normal to correct the error. In each of these three cases, DOL of both L and H contained correct data, and the common condition for these is either that AE(H) is "0", or E1(H) is "1".

The fourth case is more complex. In the previous three cases, correct data has been available in both DOL about 50ns after memory data became valid. Now with a

single data error in bits 0-15, AE(H) is a "1", E1(H) a "1", and EO(H) a "0", but L does not have sufficient information to locate the error. It is first necessary to feed back the partially generated syndromes of H back to L, and this is achieved by reversing the direction of the common bus. First L is placed in normal read mode so that L's generated check bits become disabled. Next, the partial syndromes in H are enabled onto the bus by setting \overline{OES} of H low, so that its syndrome I/O port outputs the combined Exclusive-OR of CG(H) and CIL(H), which is transferred to CIL of L. These partial syndromes then combine with CG(L) to generate valid syndrome bits in L, demonstrated by the flow path of Figure 4c. If there is, in fact, a data bit error in bits 0-15, the seventh syndrome bit will go low, allowing the remaining six bits to be decoded to locate the error as per the columns of Table 2. This switching around of the common bus, therefore, takes more time to correct the error in L, equivalent to a total time of approximately 100ns. The fifth kind of error is identified as a double error. In this case, the error flags indicate the double error and the system can take the necessary action.

A logical approach when using two DP8400s would be to first see if there is any need to reverse the common bus by monitoring AE(H), and when it is low, to output directly from DOL of both chips by setting $\overline{OB0}$ and $\overline{OB1}$ of each low. The System Data Valid flag should be set active at this time. If the AE(H) output is high and the error flags do not indicate a double error, then the common bus should be switched around and the System Data Valid signal set true. If the error is a double error, the user may utilize a number of alternatives, including the Double Complement Correct method.

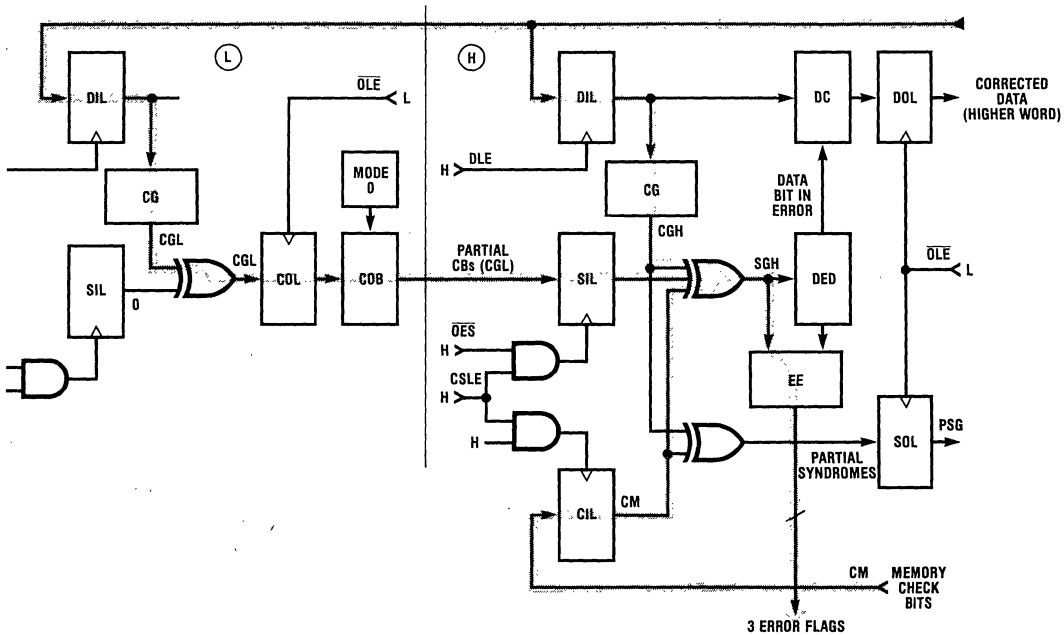


Figure 4b. E2C2 32-Bit Configuration, Detect Flow Path

Table 1. Data in to Check Bit Generate, or Data Bit Error to Syndrome-Generate Matrix (16-Bit Configuration)

GENERATED SYNDROMES	GENERATE CHECK BITS																GENERATED CHECK BITS		
	0	1	2	3	4	5	6	7	8	9	0	1	2	3	4	5			
0	0	0	1	1	1	1	1	1	1	0	1	1	1	0	1	1	0	DQ0-15	2*
1	0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	1		3*
2	1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	1		4
3	0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	1		5
4	1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	4		
5	1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	5		
																	HEXADECIMAL EQUIVALENT OF SYNDROME BITS		
																	4 8 9 7 5 1 3 9 E B D 3 C 7 F F 0		
																	3 3 2 0 2 3 2 1 3 0 0 1 2 3 2 1 1		

*C2, C3 generate odd parity.

Table 2. Data Bit Error to Syndrome-Generate Matrix (32-Bit Configuration)

SYNDROMES	L																H																GENERATED CHECK BITS					
	0	1	2	3	4	5	6	7	8	9	0	1	2	3	4	5	6	7	8	9	0	1	2	3	4	5	6	7	8	9	0	1						
0	0	0	1	1	1	1	1	1	1	0	1	1	1	0	1	1	1	0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	1	1	0	DQ0-31	5
1	0	0	0	1	0	0	1	0	1	0	1	0	1	0	1	1	1	1	1	0	1	1	0	1	0	0	0	1	1	1	0	1	1	0	5			
*2	1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	1	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	6				
*3	0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	1	0	1	1	0	0	0	1	1	1	0	1	0	1	1	1	3					
4	1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	4					
5	1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	1	0	0	1	1	0	0	1	0	1	0	1	1	1	1	2						
6	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0				
																																HEX						
																																4 8 9 7 5 1 3 9 E B D 3 C 7 F F 2 A A 1 2 2 3 8 B 9 8 1 A 3 B 9 0						
																																3 3 2 0 2 3 2 1 3 0 0 1 2 3 2 1 3 1 4 6 6 5 4 5 3 4 6 5 2 7 6 7 1						

*CG2, CG3 generate odd parity.

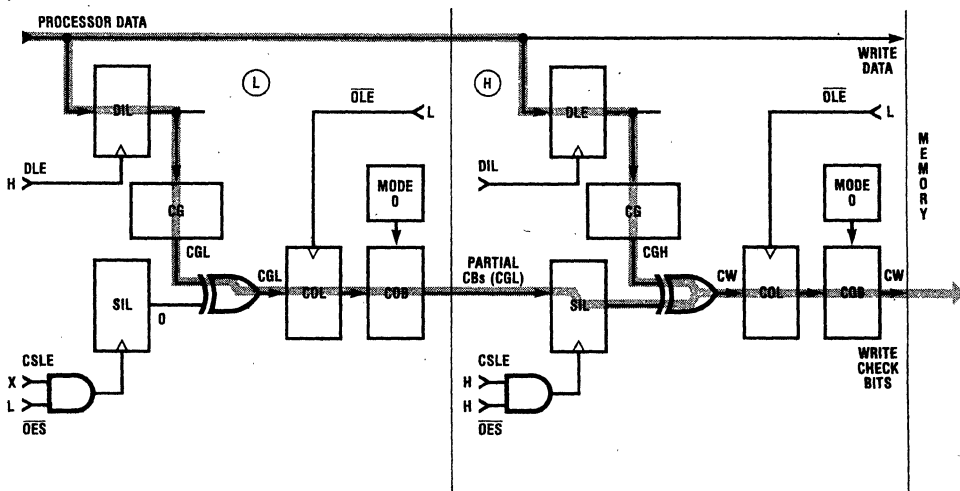


Figure 4c. E²C² 32-Bit Configuration, Write Flow Path

**Table 3. Error Flags After Normal Read
(32-Bit Configuration)**

AE (H)	E1 (H)	E0 (H)	E0 (L)*	Error Type
0	0	0	0	No error
1	1	0	0	Single check bit error
1	1	1	0	Single data bit error (H)
1	1	0	1	Single data bit error (L)
1	0	0	0	Double bit error
All Others				Invalid conditions

*E0 (L) is valid after transfer of partial syndromes from higher to lower.

This approach to wider data width error detection and correction is termed the cascade configuration, and it requires only the one additional DP8400. The cascade approach can be used with up to five DP8400s controlling 80 data bits. The advantage is that only one additional DP8400 is required per 16 data bits, although write and read times become progressively slower as the number of DP8400s is increased. This is because of the time taken for the generated check bits to ripple through from the lowest to highest chips when writing and detecting, and then ripple back the other way for correcting.

In many memory systems, speed is of utmost importance and for faster systems, it is possible to connect the DP8400s in a parallel configuration using additional ICs. Application Note AN-308 describes this approach in detail.

The user may, therefore, select one of these approaches (or a combination of both) for systems using memory data widths of more than 16 bits.

Diagnostic Capabilities of the DP8400

The DP8400 has been designed with system fault diagnosis in mind. In fact, it is possible under microprocessor control with the DP8400 in situ on the memory board to fully test every gate inside the DP8400 activated in normal operation, and also to diagnose all memory check bits. The DP8400 has two main diagnostic modes—modes 2 and 6. In other words, with M1 set high and M0 set low, information can be written to or read from the chip.

Mode 6 allows the memory check bits to be read onto the higher byte bits 8–14, and syndromes to be read on the lower byte bits 0–6, as shown in *Figure 5a*. The remaining two bits, 7 and 15, are the error flags E1 and E0 that were valid when mode 6 was entered. The syndrome bits will be the internally generated syndromes if \overline{OES} is low (mode 6A), or external syndromes input on the syndrome I/O port if \overline{OES} is high (mode 6B). The external syndromes could be obtained from an error logger/syndrome injector unit—this is an error logger with the capability of injecting syndromes back to the DP8400. Therefore, by being able to read the externally stored syndromes, the microprocessor can monitor or store the syndromes whenever needed.

Mode 2 transfers system data from the higher byte into CIL, instead of DIL, to simulate check bits. This can be used in three ways. First, as shown in *Figure 5b*, the simulated check bits can be latched in CIL by taking CSLE low. If the DP8400 is now set to normal read, mode 4, and new data is presented then, provided DLE is high

and CSLE is kept low, the DP8400 will perform a normal read operation as if it were reading memory check bits. The results of this simulated read may be checked by enabling DOL to see if an error (if inserted) was corrected. Or as a further check, by entering mode 6, the predicted generated syndromes and error flags may be checked. Second, also while in mode 2, the simulated check bits appear at the check bit port (from the data bus higher byte) available to be written to the check bit portion of memory as shown in *Figure 4c*. \overline{OLE} is set high before the original simulated check bits are removed and then memory data is subsequently placed on the data bus. A write to memory will now write known data and simulated check bits to the selected location. By writing known data to the memory check bits in mode 2, and then reading the memory check bits in mode 6, each check bit in each location can be validated. Third, it is possible in mode 2 with \overline{OES} low to transfer data from the higher byte to the syndrome I/O port, also shown in *Figure 5c*. But first the generated check bits must be all low. This is attained by previously loading all “1”s into DIL in an earlier cycle. This is useful when using an error logger in conjunction with the DP8400 to feed the syndrome word into the logger whenever an error occurs.

Error Logging with Syndrome Injection Capability

An important application of the dedicated syndrome I/O port is for error logging. This is because the internally generated syndromes derived during reading are available on this port, provided \overline{OES} is set low. These syndromes indicate the exact location of a single error, whether it is in the data bits or check bits; they are therefore useful to be stored for error logging. Every time an error occurs when indicated by error flag AE, the syndromes corresponding to this error can be logged.

The syndrome word can be fed from SOL via the Syndrome Output Buffer onto the external syndrome bus. An Error Logger connected to this bus, as shown in *Figure 6*, will store the syndrome word in the same location as the corresponding address of each error that occurs. An intelligent error logger will differentiate between new errors and ones that have occurred previously, by logging only new errors and ignoring ones that have already occurred. An easy way to determine this would be to compare the incoming memory address with the address of errors contained in the logger. If a match is not found and an error occurs, the new address and corresponding syndromes are logged. If a match is

found, then whether an error occurs or not, no further action is necessary. Tag bits may be provided to indicate whether the error is hard or soft.

For example, if an error has already been logged at a particular address and that address is re-written to, then if the error repeats subsequently, it is a hard error, and if not, it is a soft error. So, if a tag bit is set when a write occurs to a previously logged address and a subsequent error is detected at that address, a second tag bit is set indicating a hard error. A better approach would be to have the DP8400 correct and rewrite to the same location all in the same cycle, as soon as a single error is detected. The first error detected in a location is classified as a soft error until it recurs, and if an error does recur, a tag bit is set to indicate a hard error. It is assumed here that multiple soft errors will not occur in the same location.

Now that the error logger contains error information, it is necessary for the microprocessor to retrieve it. The DP8400 makes this easy, because the external syndrome bus data can be transferred to the data bus as described for operation in mode 6. If the error logger is made capable of outputting stored syndromes, and subsequently outputting the corresponding address one byte at a time, then all the relevant information can be retrieved by the microprocessor. The user may choose to store this in nonvolatile memory in the event of a power failure. When power returns, it will be desirable to restore this information back to the error logger, and this can be achieved by first loading DIL with all "1"s to create all generated check bits low. Now the addresses and syndromes can be loaded from the higher byte of the microprocessor through the syndrome I/O port one byte at a time, with DP8400 in mode 2, to the error logger.

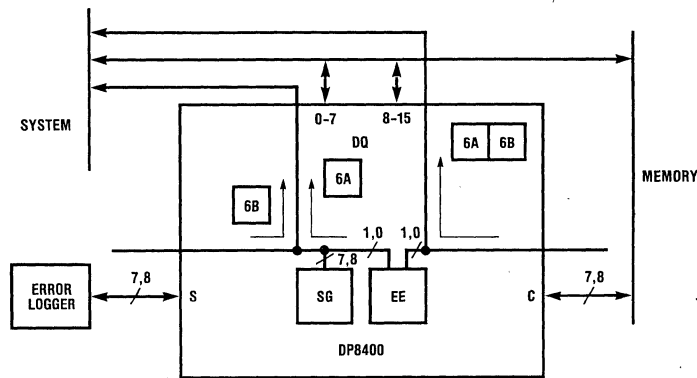


Figure 5a. Read Internal Generated Syndromes and Check Bit Port (Mode 6A) or Read Syndrome Port and Check Bit Port (Mode 6B)

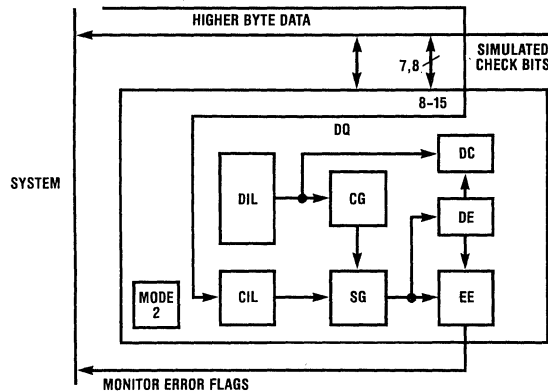
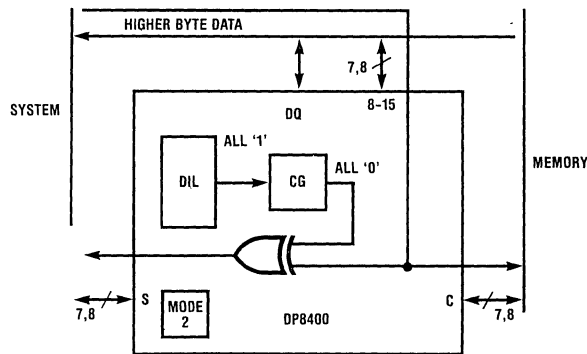


Figure 5b. Diagnostic Read — Compare Simulated Check Bits with Check Bits Generated from Data Stored in Previous Cycle



1) DIAGNOSTIC WRITE: WRITE HIGHER DATA BYTE TO CHECK BIT BUS (MODE 2)

2) TRANSFER HIGHER DATA BYTE TO SYNDROME BUS (MODE 2, PREVIOUS CYCLE LATCHED '1's IN DIL TO MAKE CG=0)

Figure 5c. DP8400: Mode 2

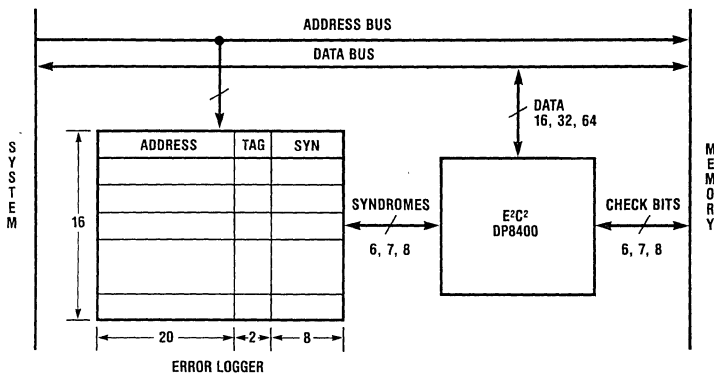


Figure 6. Error Logger Connected to DP8400 Syndrome Port

Correcting Double Errors Using the Error Logger

It is possible to take the error logging function one stage further. As described so far, the error logger has been storing single errors (data bit or check bit). What if a double error is detected? If it is detected without any previous history at that address, one solution would be to perform a Double Complement to attempt to correct both errors. If this is not done, no useful information can be obtained. If both errors are corrected, the error logger records the syndromes of both, and tags whether they were both hard, or one hard and one soft. But, if there is a previous history at this address of a single error, then it is fair to assume that the second error has subsequently occurred. In this case, if the error logger could be made to inject the syndromes of the first error into the DP8400, the DP8400 would correct this error so that its DOL would then contain data with one error (if both errors are data bit errors). It is necessary at this point to wrap-around DOL back to DIL and allow the DP8400 to correct the second error. This approach is much faster than the Double Complement approach and at the same time offers full error logging capability.

Any Double Error Correction Using The Double Syndrome Decode Approach

The data sheet shows how the DP8400 can perform double error correction using the Double Complement Approach, provided at least one of the errors was hard. For very large memories, this may not be adequate, as some systems will require total double error correction capability—quickly, without having to wait two additional memory cycles. Some of these systems will also require triple error detect capability. Fortunately, the matrix of the DP8400 has been configured to allow both of these capabilities. Most modern error detection/correction matrices use a modified version of Hamming's original code. The Hamming code allows single errors to be corrected, however, two errors may not be detected as such. For 16 data bits, five check bits are required. Modified Hamming codes allow double error detect capability, as well, by arranging that the Exclusive-OR of the syndrome words of any two bits in error produces an even parity syndrome word. A parity check on the syndrome bus will, therefore, indicate two errors (or no error, but in this case, the Any Error flag will be inactive). For 16 data bits, six check bits are required for single/double error detect and single error correction capabilities.

The DP8400 has a matrix that goes one step further by using a version of the Nelson code. This costs no additional on-chip gates to those required for a Modified Hamming code. To be able to correct any two errors, it is necessary to be able to determine their location, and no present version of the Modified Hamming code is able to do this. There are matrices that do exist that can generate 12 check bits from 16 data bits (or 14 check bits from 32 data bits) for writing, and then generate 12 (or 14) syndrome bits when reading, so that the location of both errors can be determined and corrected. But, because most applications do not require this degree of integrity and associated expense, they are not very popular. It would be ideal if two DP8400s could be configured as in Figure 7a, with each generating a different set of check bits and a different set of syndrome bits so that the double syndrome word could be unique and decodable for any two bits in error. Fortunately, National Semiconductor has achieved this by incorporating a feature called the Rotational Syndrome Word Generator, which uses rotated data to the secondary DP8400.

The primary DP8400 generates check bits when writing, and syndrome bits when reading, as in a normal 16-bit system. But the data port of the secondary DP8400 receives data shifted by a number of bits, usually one bit. In other words, for this secondary chip, system data bit 0 connects to DQ1, system data bit 1 to DQ2, etc. Each DP8400 has its own dedicated six memory check bits, which are obviously different from each other due to the data shifting on the secondary DP8400. The Nelson code is such that during a read, not only does each DP8400 generate a different set of syndrome bits, but the double syndrome word (comprising 12 bits for 16 data bits) is unique for any two bits in error. It is necessary to be able to output these syndromes as they occur and to do this, \overline{OES} of both chips is set low during the time memory data is valid.

Now that we have a unique double syndrome word for any two bits in error, it is necessary to decode it to correct both errors. The easiest way to do this is to connect the double syndrome word to the address inputs of a registered PROM (a PROM with latched data out) as shown in Figure 7b. In this example, 12 syndrome bits require 4k addressing capability, and 32k registered PROMs will be made available soon. Some of the addresses of the RPPROM will be used for double errors and each address will be unique for any two bits in error. The

corresponding data out could, therefore, contain one of the syndrome words. Double errors may be caused by two data bit errors, a data bit and primary check bit error, a data bit and secondary check bit error, a primary and secondary check bit error, or two errors in either primary or secondary check bits. In these cases, if the RPPROM address stores the syndrome word for one of the two errors, this will be available at the output of the RPPROM when enabled.

First of all, this data must be latched in the RPPROM register, and then the \overline{OES} input to each DP8400 must be set high to deactivate the two syndrome output buffers. Next, the RPPROM data must be enabled onto the primary syndrome bus so the primary DP8400 can enter this syndrome word, representing one of the two bits in error with CSLE high. At the same time, the primary DP8400 must be set to mode 7 so that the syndrome word appears on the internal syndrome bus, replacing the generated syndromes. If \overline{OLE} is now set from low to high, DOL will contain either one or no error, depending on where the two errors were located. In other words, the DP8400 has just corrected one of the errors. By setting \overline{OLE} low, then disabling memory and enabling $\overline{OB0}$ and $\overline{OB1}$ of the primary DP8400, this data is output on the data bus and back into the DIL with DLE high. There is now only one data error, and this can be corrected by setting the DP8400 to normal read, mode 4.

Thus, both errors have been corrected at a fairly fast rate. For example, for a 50ns RPPROM, the total time to generate double syndromes, feed back a one-error syndrome word to the primary DP8400, correct it, wraparound, and correct again, may take less than 120ns total.

Only a few of the addresses in the RPPROM are required for double errors. Some double syndrome words represent single errors and triple errors. All single bit errors also produce a unique double syndrome word different from all double bit errors.

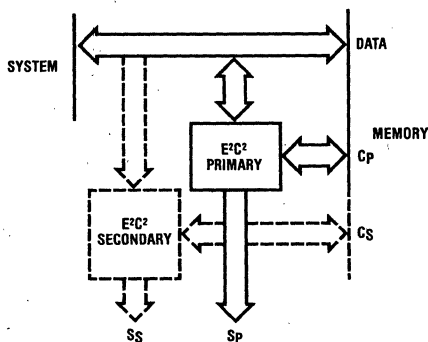


Figure 7a. 2 Different Generators

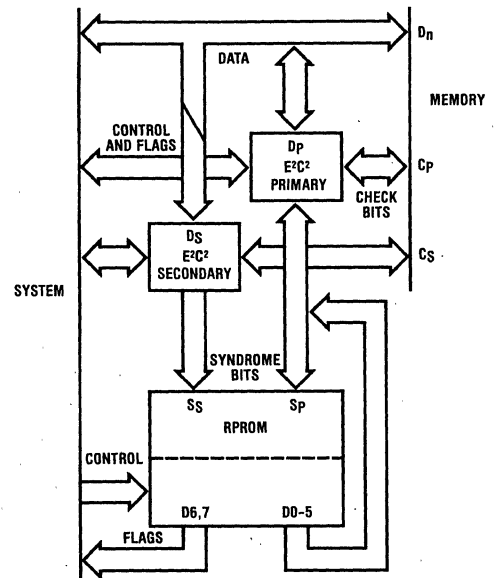


Figure 7b

In fact, nearly all triple bit errors produce unique double syndrome words different from single and double bit errors. Those that do not produce unique double syndrome words, duplicate double syndrome words of other single, double, and triple bit errors; however, these comprise only about 5 percent of the total. We can say, therefore, that this approach will correct not only all double bit errors, but will detect 95 percent of all triple bit errors. Note that with error correction systems utilizing the modified Hamming code, the majority of triple bit errors are interpreted as single bit errors and falsely corrected as such. It is up to the designer to determine the chances of three errors occurring in a memory location, and the (likely) consequences that they will be falsely corrected. If this condition is undesirable, then the Double Syndrome Decode Method offers greatly enhanced integrity; in fact, if the three errors detected do have a unique double syndrome word, they can be corrected. As stated, no presently used Modified Hamming code offers a unique double syndrome word for multiple errors; this is only possible with a Nelson code. This example was largely for 16 data bits, but the idea will work for other data widths.

In the 16-bit example, the R PROM has to output only six bits representing the syndrome bits of a bit in error. This leaves two spare bits which can be used as flags, and the user can program his R PROM accordingly. One solution is to use these flags to indicate the type of action required — whether to correct at all, correct once, or correct twice by wrapping around.

Block Diagram of the DP8400

This Application Note discusses first the single error correction, showing a simplified block diagram of the chip for both a write cycle to generate check bits, and a read cycle to detect errors and correct single bit errors.

The most important requirement when accessing memory is that these operations be performed with minimal memory delays. The DP8400, therefore, has been structured internally to minimize series propagation delays through the chip. A full block diagram of the DP8400 is shown, and first impressions are that there might be excessive delays in the various paths due to the additional blocks that have been added to the basic functional block diagram. In fact, this is not the case, because the DP8400 has been configured in bipolar Schottky logic and uses the AND-OR-INVERT gate in many of the blocks. This type of gate structure is used in multiplexers, Exclusive-OR gates and fall-through latches. It is possible, therefore, to combine these functions into one wide gate, reducing the propagation delays through some of these blocks to that of one gate. For example, the check bit output latch COL receives its input from an Exclusive-OR gate followed by a multiplexer. These three functions can be combined into one wide gate, and this greatly reduces the time taken to generate check bits.

The DP8400 — A Versatile Error Checker/ Corrector for All Applications

It was shown earlier how the DP8400 was able to detect single and double errors, and correct single errors. For 8- and 16-bit systems, these could easily be accomplished with a minimum of extra circuitry. The DP8400 can also be used in complex high integrity systems. In fact, investigations are still progressing as to its immense capabilities. It is the only error correction circuit capable of these features, and yet it still provides very fast throughput. For these reasons, the DP8400 should become the industry standard error correction chip for the foreseeable future.

DP8400s in 64-Bit Expansion

National Semiconductor
Application Note AN-308
Chuck Pham
June 1982



The purpose of this Application Note is to provide memory designers with detailed information on the DP8400 parallel expansion method. This method allows fast check bit generation, error detection, and error correction. A thorough understanding of the 16-bit implementation is a prerequisite. Included in this note are the following: error correction expansion matrix; detailed steps for check bit generation, error detection and error correction; an example of a single error correction; and the detailed wiring diagram for the 64-bit configuration.

The Error Correction Expansion Matrix

For a 16-bit word, the DP8400 reads data between the processor and memory, with its 16-bit bidirectional data bus connected to the memory data bus. The DP8400 uses an encoding matrix to generate six check bits from the 16 bits of data. This 16-bit matrix contains 16 unique syndrome patterns corresponding to each error location which allows the DP8400's Data Error Decoder (DED) to identify the data error location.

The DP8400 is easily expandable to other data configurations. For a 32-bit data word with seven check bits, two DP8400s are used. Three DP8400s can be used for 48 bits, four DP8400s for 64 bits, and five DP8400s for 80 bits, all with eight check bits. In order to expand the DP8400, additional check bits are required to provide the unique characteristic of the single data error syndrome. For expansion beyond 24 bits, check bits 6 and 7 (C6 and C7) are used. Note that these check bits can be configured to be always either zero or word parity, depending on the input voltage level of the Expansion Pin (XP). By rearranging all eight check bits (C0- C7) of each DP8400, we can obtain many different matrices that meet the above requirement. One of these is shown in Table 1. For illustration, this matrix will be used throughout this application note to clarify the E²C² expansion concept.

Check Bit Generation, Error Detection And Error Correction

Check Bit Generation (Figure 1)

In the Check Bit Generation mode, all four DP8400s are set to mode 0, normal write. The 64 bits of data from the system data bus are enabled into the Data Input Latches (DIL) of each DP8400. The individual Check Bit Generators (CG) of the four DP8400s then produce eight parity bits, or partial check bits, derived from the input data. (Note that all the syndrome input latches should be cleared so that only the partial check bits will pass through the Check Bit Output Latches/Buffers (COL and COB)). In the normal write mode, the COBs are always enabled onto each check bit port. This allows the partial

Table 1. Data Bit Error to Syndrome-Generate Matrix, 64-Bit Configuration

The partial code of device 0:

Error Locations (Data Bit Numbers)																
0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	
0	0	1	1	1	1	1	1	0	1	1	1	0	1	1	1	C0
0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	C1
1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	C2
0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	C3
1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	C4
1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	C5
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C6
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C7

The partial code of device 1:

16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	
0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	C1
1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	C5
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C6
1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	C4
0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	C3
1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	C2
0	0	1	1	1	1	1	0	1	1	1	0	1	1	1	1	C0
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C7

The partial code of device 2:

32	33	34	35	36	37	38	39	40	41	42	43	44	45	46	47	
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C6
0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	C3
1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	C5
1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	C4
1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	C2
0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	C7
0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	C1
0	0	1	1	1	1	1	1	0	1	1	1	0	1	1	1	C0

The partial code of device 3:

48	49	50	51	52	53	54	55	56	57	58	59	60	61	62	63	
1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	C4
1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	C5
0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	C3
1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	C6
1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	C2
0	0	1	1	1	1	1	1	0	1	1	1	0	1	1	1	C0
0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	C1
1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	C7

check bits to be combined externally in the eight 74S280s' parity generators/checkers to produce eight composite check bits. Table 2 shows how these check bits are generated.

Table 2. Composite Check Bit Generation

Ccomp. 0	=	C(0)0	⊕	C(1)1	⊕	C(2)6	⊕	C(3)4
Ccomp. 1	=	C(0)1	⊕	C(1)5	⊕	C(2)3	⊕	C(3)5
Ccomp. 2	=	C(0)2	⊕	C(1)6	⊕	C(2)5	⊕	C(3)3
Ccomp. 3	=	C(0)3	⊕	C(1)4	⊕	C(2)4	⊕	C(3)6
Ccomp. 4	=	C(0)4	⊕	C(1)3	⊕	C(2)2	⊕	C(3)2
Ccomp. 5	=	C(0)5	⊕	C(1)2	⊕	C(2)7	⊕	C(3)0
Ccomp. 6	=	C(0)6	⊕	C(1)0	⊕	C(2)1	⊕	C(3)1
Ccomp. 7	=	C(0)7	⊕	C(1)7	⊕	C(2)0	⊕	C(3)7

Notes:

Ccomp: composite check bit.
C(X)N: the partial check bit N of device X.
(Refer to Table 1 for clarification.)

To aid in fast error detection during memory read cycles, these composite check bits are complemented and written into memory along with the system data. If the system data has vacated the data bus, the Output Enables (OB0 and OB1) must be set low so that the original data word with its eight composite check bits can be written into memory.

Detection Mode (Figure 2)

In the Detection mode, again all the DP8400s are set to mode 0, normal write, then the partial check bits derived from the memory data bits are generated in a manner similar to that described for the check bit generation mode. These partial check bits are then associatively compared with the memory check bits in the eight 74S280s to produce eight external Composite Syndrome bits. As explained in the check bit generation mode, the composite check bits are complemented before being written into memory. This shows why complemented Composite Syndrome bits are produced instead of true composite syndromes. Then, if any bits on the Composite Syndrome bus go low, this will cause the 74S30 NAND gate to go high, giving the Any Error indication. If there is no error, all Composite Syndrome bits remain high. These Syndrome bits are also latched into the 74ALS533 Octal D-type Transparent Latch (with inverted output). The composite syndromes are then fed into the syndrome ports of the DP8400s in different combinations for each, for error-type determination and/or error correction.

Correction Mode: (Figure 3)

Upon receiving the Any Error indication during the detection mode, it takes an additional step to determine the error type and to correct a single data error. All the DP8400s should be set to mode 7B (which is mode 7 with OES high), this mode enables the external syndromes directly to the Syndrome Generator (SG) and then the Data Error Decoder (DED) of each chip. For a single data error, the input syndrome will be unique for that error location; consequently, only one DP8400 can decode that error location and correct that bit. The other three do not indicate an error and do not change their data output latch contents. This corrected data can be output to the system data bus by means of OB0 and OB1. The DP8400 that decodes the data error location will indicate a single data error, while all others indicate a check bit

error. If there was a single check bit error or a double bit error, then all the DP8400s will indicate a check bit error or a double bit error, respectively, through their error flags.

An Example of a Single Data Error Correction

Assuming all zero data is to be written into memory, we obtain the following set of partial check bits for all DP8400s:

C0 = 0	C4 = 0
C1 = 0	C5 = 0
C2 = 1	C6 = 0
C3 = 1	C7 = 0

Note that each DP8400 contains the basic 16-bit matrix (C0-C5). Therefore, the first six partial check bits are the same for all devices; only C6 and C7 are different. With the 64-bit configuration using the above 64-bit matrix, C6 = C7 = 0 (by connecting XP directly to V_{CC}) for the devices 0, 1, and 2; and C6 = C7 = word parity (by leaving XP pin floating) for the device 3. However, with all zero data, word parity is also zero (even parity). Therefore, the above partial check bits are obtained.

Using the formulas given in Table 2, the composite check bits are as follows:

Ccomp. 0	=	0	⊕	0	⊕	0	⊕	0	=	0
Ccomp. 1	=	0	⊕	0	⊕	1	⊕	0	=	1
Ccomp. 2	=	1	⊕	0	⊕	0	⊕	1	=	0
Ccomp. 3	=	1	⊕	0	⊕	0	⊕	0	=	1
Ccomp. 4	=	0	⊕	1	⊕	1	⊕	1	=	1
Ccomp. 5	=	0	⊕	1	⊕	0	⊕	0	=	1
Ccomp. 6	=	0	⊕	0	⊕	0	⊕	0	=	0
Ccomp. 7	=	0	⊕	0	⊕	0	⊕	0	=	0

Note that these composite check bits are complemented before they are written into memory. Thus, the memory check bits read later from memory are 1100 0101.

If an error has occurred in the data position 35 which is bit 3 of device 2, then the partial check bits C(3)N produced during the detection mode are as follows:

C(3)0 = 1	C(4) = 0
C(3)1 = 1	C(5) = 0
C(3)2 = 0	C(6) = 0
C(3)3 = 1	C(7) = 0

The partial check bits of other devices are unchanged. Consequently, the newly generated composite check bits (Ccomp) and the total syndrome bits are:

Bit #	Newly Generated Composite Check Bits	Memory Check Bits	Composite Syndrome
0	0	⊕	1
1	1	⊕	0
2	0	⊕	1
3	1	⊕	0
4	0	⊕	0
5	1	⊕	0
6	1	⊕	1
7	1	⊕	1

7-118

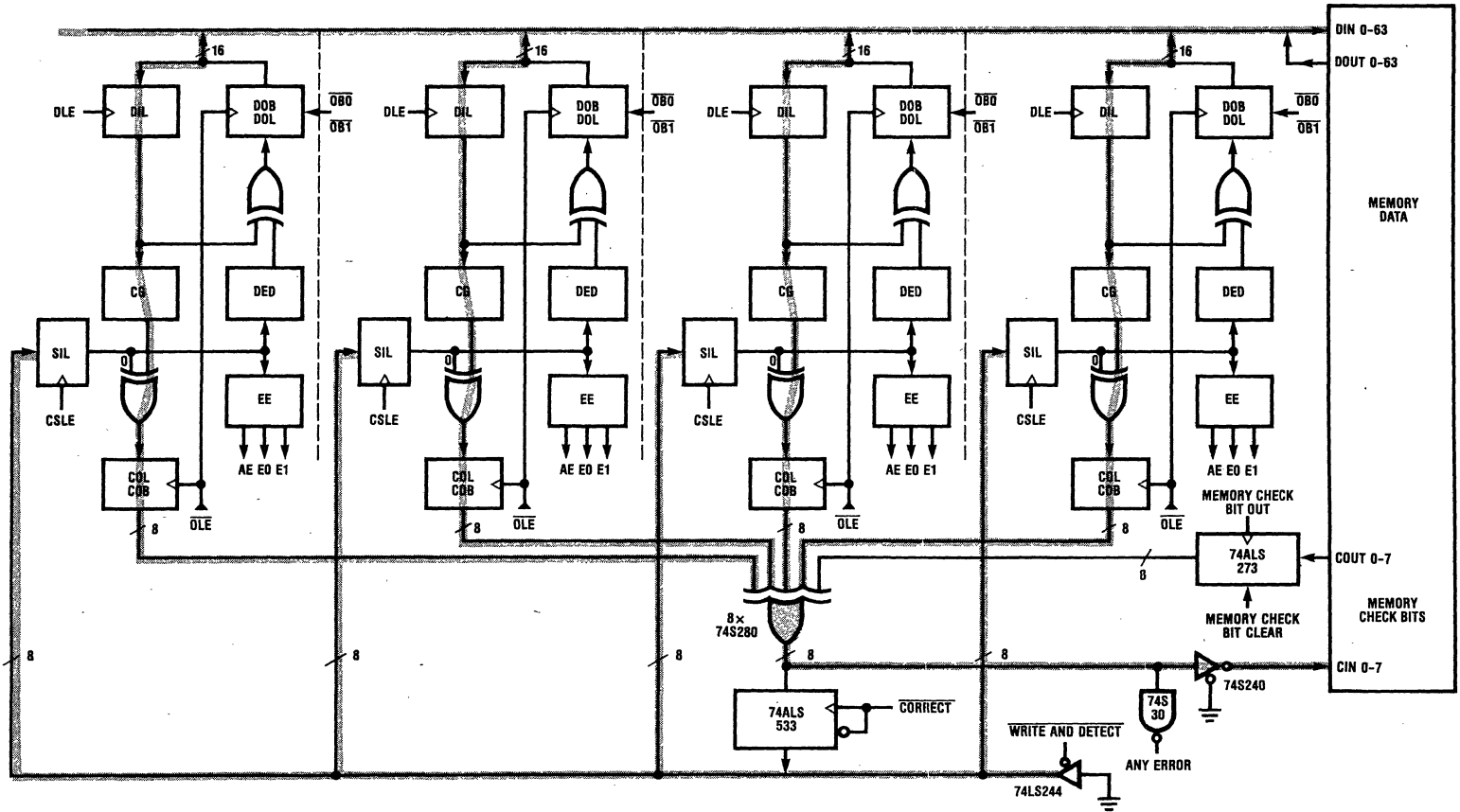


Figure 1. E²C² Simplified Block Diagram—
64-Bit Parallel Expansion, Check-Bit Generation

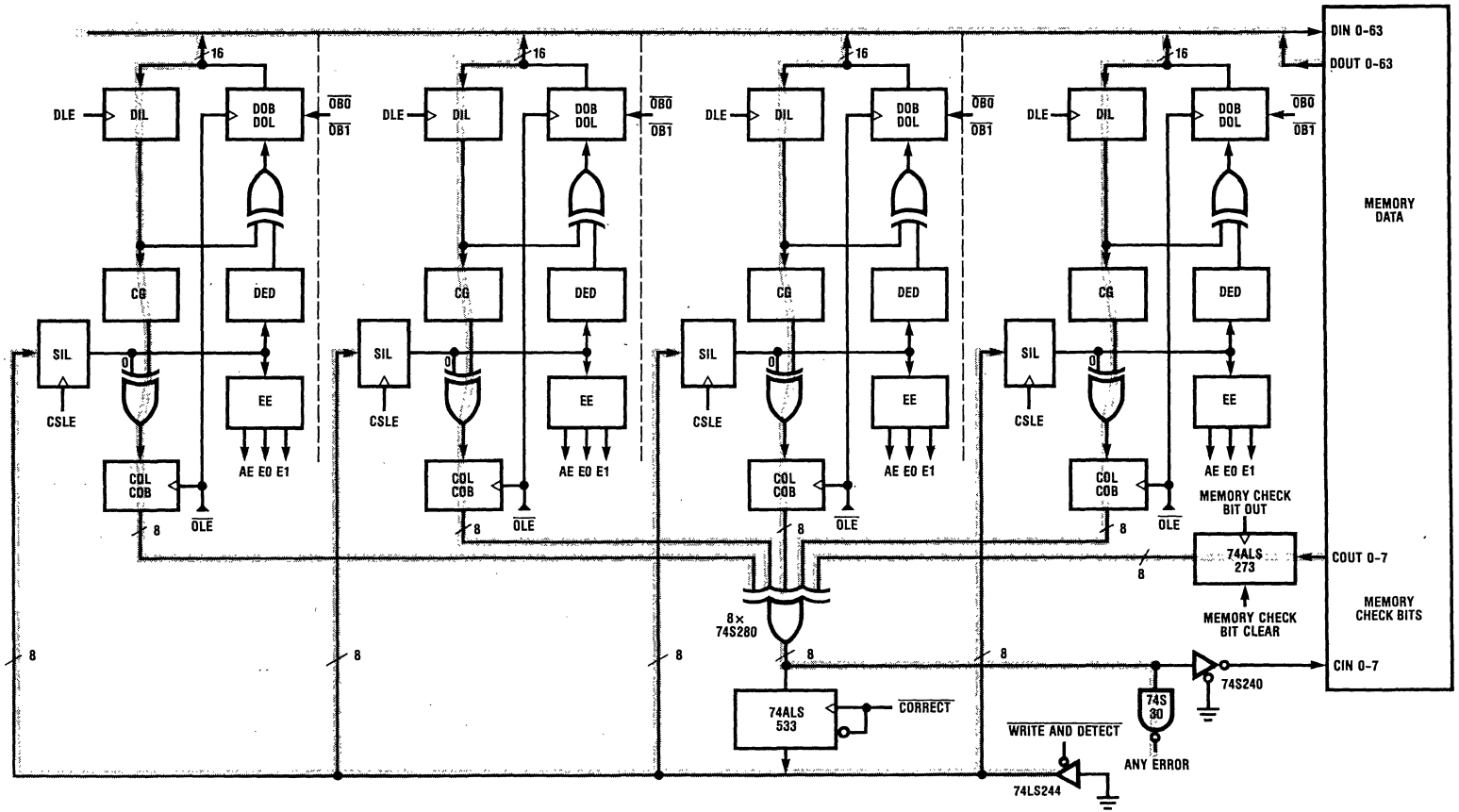


Figure 2. E²C² Simplified Block Diagram —
64-Bit Parallel Expansion, Error Detection

7-120

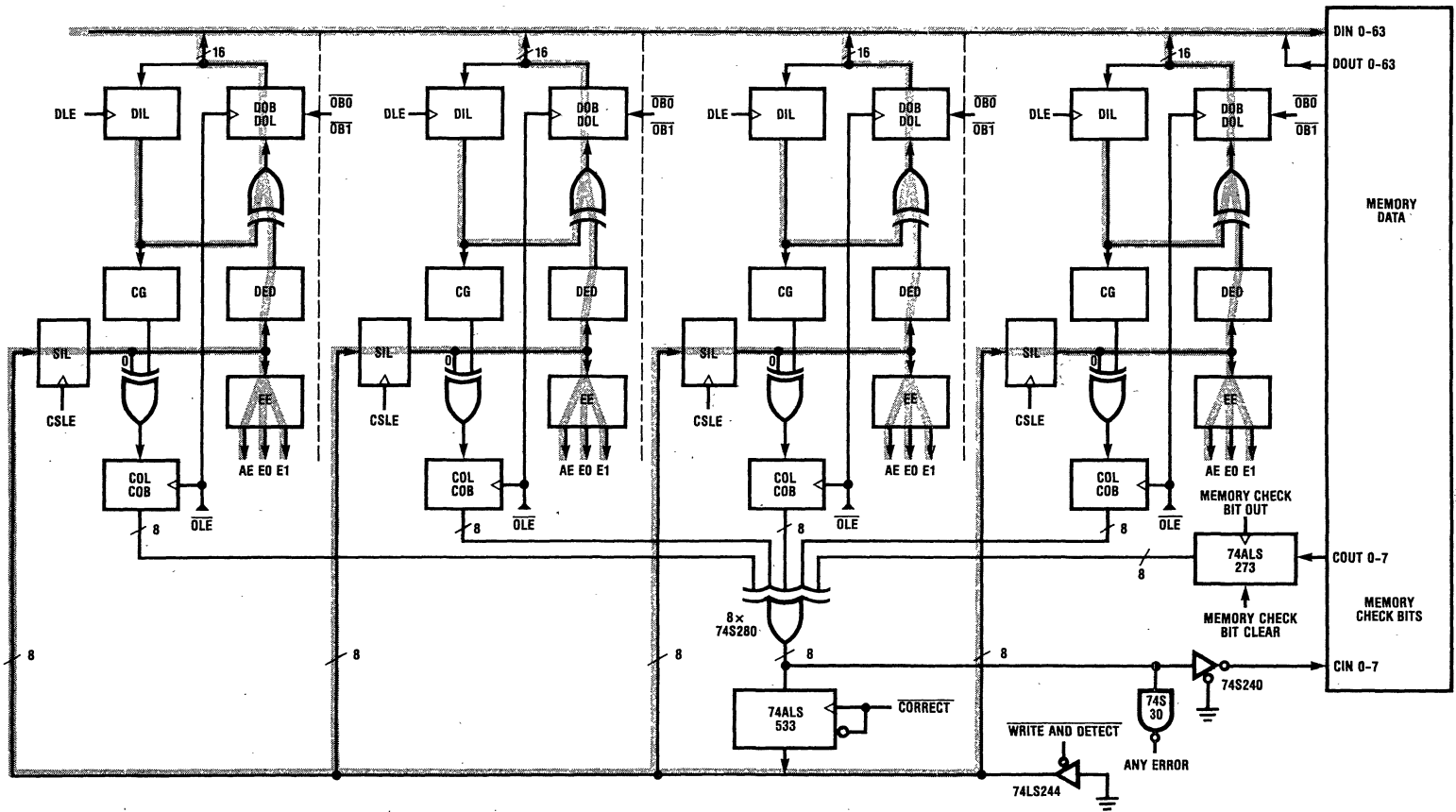


Figure 3. E²C² Simplified Block Diagram—
64-Bit Parallel Expansion, Error Determination
and Correction

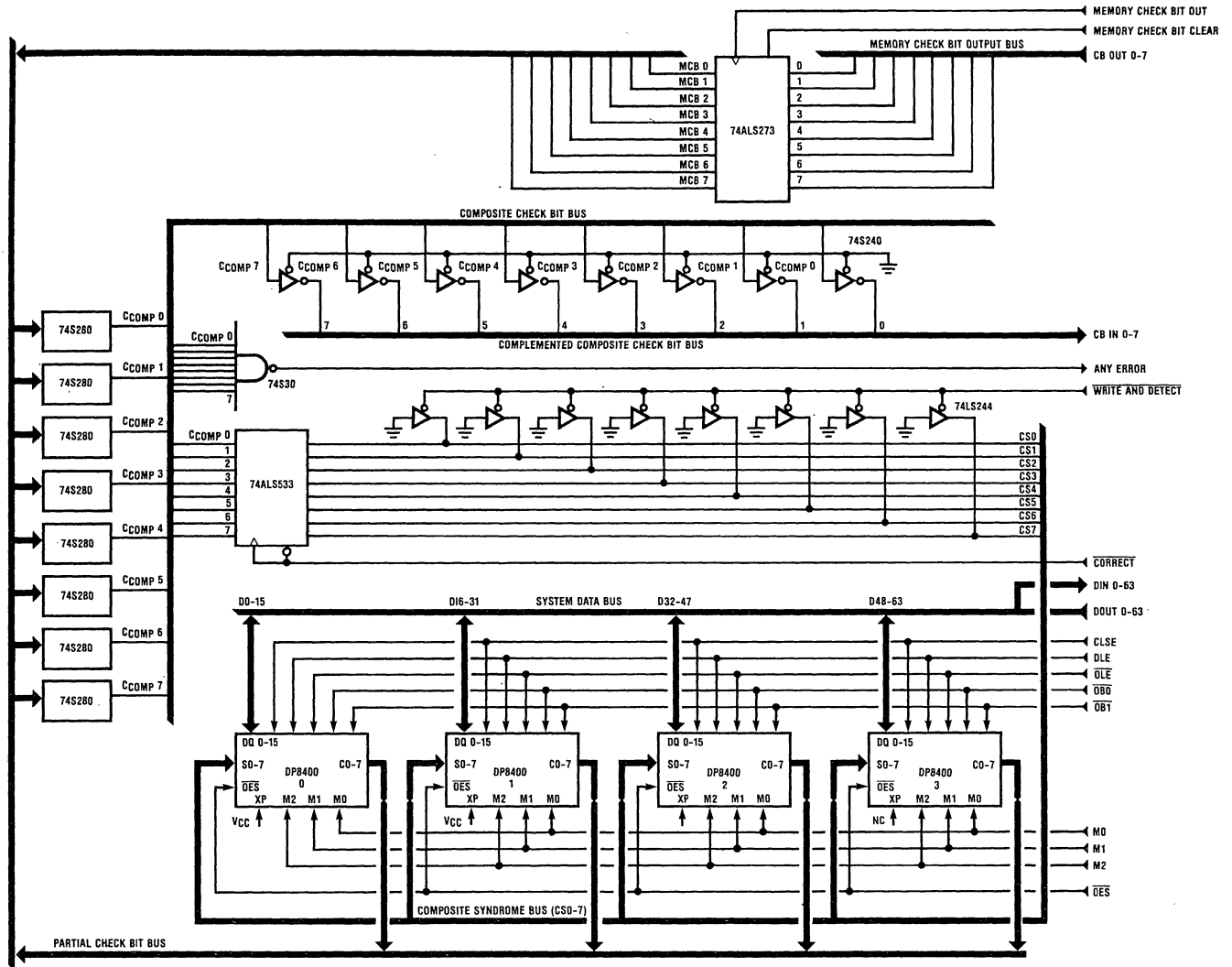


Figure 4. E²C² 64-Bit Parallel Expansion, Detailed Block Diagram



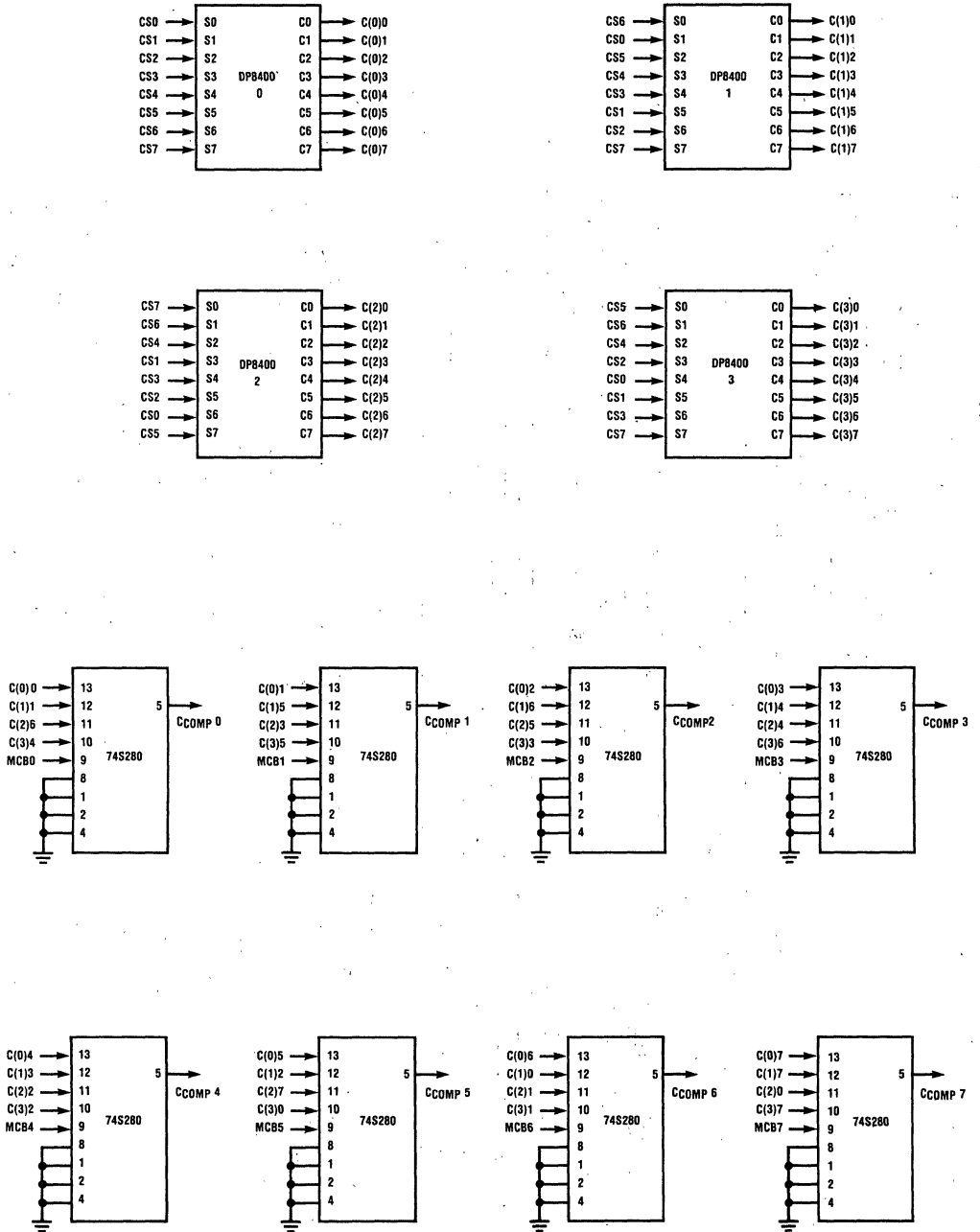


Figure 5. E²C² 64-Bit Parallel Expansion, Detailed Connection Diagram

The composite syndrome 1101 0000 is that of the error location 35. Since the syndrome is unique and fed re-ordered to each DP8400, only device 2 will recognize this syndrome pattern and complement its data bit 3. Then the corrected data can be output to the system data bus when $\overline{OB0}$ and $\overline{OB1}$ of all four DP8400s go low. Devices 0,

1, and 3 all output the same data they received from memory. Only device 2 changes its (erroneous) data. Refer to Figure 6 below for the timing diagrams of a memory write and memory read cycle (detect then correct).

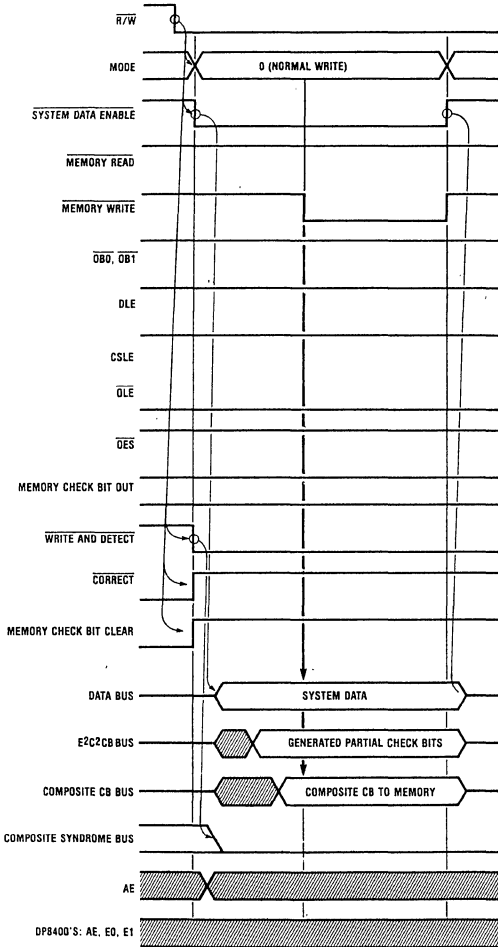


Figure 6A. E²C² 64-Bit Parallel Expansion Memory Write Cycle

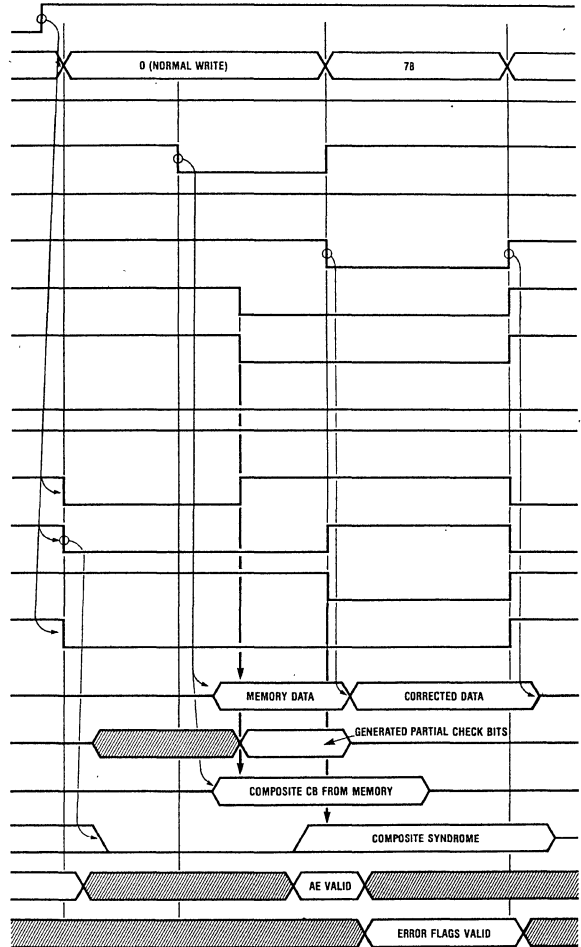


Figure 6B. E²C² 64-Bit Parallel Expansion Memory Read Cycle (Detect Then Correct)

ERROR CORRECTION THE HARD WAY

A double complement correct cycle in an ECC system forms a sophisticated double-bit error correction and management system

by Bob Nelson

The use of parity, the most common error detection method, can be expanded from simple error detection in data words to the correction of single-bit errors by means of a double complement correct cycle. The double complement method can also be used to advantage in combination with error checking and correction systems to detect and correct hard and soft combinations of double-bit errors, provided no more than one of such errors is soft. In addition, this technique points the way to more sophisticated double-bit error correction and error management systems.

A parity bit is assigned a value of 1 or 0 on the basis of the number of 1s in the data word. The value of the parity bit depends on whether the parity system chosen is odd or even. Thus, in an odd parity system, the sum of the 1s in the data word and the parity bit will always be odd, whereas in an even parity system, the sum of the 1s in the data word and the parity bit will always be even (Fig 1). All examples in this discussion, except for those in Fig 1, use odd parity. A single parity bit can be used to detect a single-bit error occurring during a memory read cycle, and the technique can be expanded to provide even further error handling.

Parity error detection and correction

During a memory write, the parity bit which is created as a result of the data is written to the memory along with the data word for storage. When a read cycle occurs, parity generation is again performed on the data word, creating a new parity bit, which is then compared with the original parity bit read from memory. If a difference exists between the two parity bits, an error has occurred. Although this error cannot be located with the information given, and may have occurred in any bit lo-

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Data Word	Parity	Number of 1s	System
10001010	1	4	even
10001010	0	3	odd
01101001	1	5	odd

Fig 1 Odd and even parity. Value of parity bit is generated to satisfy chosen parity system (even or odd) so that sum of all 1s, including parity bit, will conform to even or odd parity system

cation in the data word or even in the parity bit, if it is a hard error, its location can be determined through the use of additional memory cycles.

If an error is detected during a memory read cycle, a simple procedure called the double complement method will determine if the error is hard, and, if so, correct it. The method includes a routine during which the suspect data and parity bit are complemented and presented to the same location in memory for a write cycle. Following the write, a read cycle is performed, and if the error is a hard error, the memory will repeat it by providing the data with the error bit complemented again. After a second complement, the data will be correct. At the end of such a correct cycle the memory contains the complemented data, and one additional write cycle must be performed to restore the data in memory (Fig 2).

During a double complement correct cycle involving a data word containing an even number of bit locations, the parity test is performed after the second read and before the second complement. If the error is hard, a parity error will once again be detected following the second read. If the error is soft, a parity error will not result following the second read. For data words containing an odd number of bit locations, parity testing

1st write	11010011	0	original data
1st read	11010111	0	PE (parity error)
D → D	00101000	1	data are complemented
2nd write	00101000	1	complemented data
2nd read	00101100	1	PE (parity error)
D → D	11010011	0	data are complemented
			↑ hard error location

Fig 2 Hard error correction with parity. Single parity bit can be used to correct single-bit hard error with double complement method. On each memory read, original parity bit is read and new parity check is done on bits in data word. New parity bit is then compared with that read for validity

Write	0000010001000000	000101	
Read	00000100010100000	000101	error in 11
Generate	00000100010100000	010110	new check bits
XOR check bits		010011	syndrome bits

Fig 7 Generating syndromes for locating error. Syndrome word is result of exclusive OR (XOR) of error check bits. No-error condition would result in syndrome word of all 0s

a value of 1 for the parity bit. For check bit 1, the selected location of correspondence is 9 only. Check bit 1 is assigned a value of 0 for odd parity. The complete set of check bits for this particular word is 000101 (05 HEX).

After check bit generation, the data and check bits go to the memory. During the read a new set of check bits are generated and compared against the check bits read from memory. The results of this check bit compare, an exclusive OR (XOR) function, are the syndromes (Fig 7). The single error indicating syndrome word is unique and is interpreted by the syndrome decoder to indicate the column in the matrix corresponding to the error location. The matrix or code is therefore a check bit generator for data, but a syndrome generator for error locations.

The...method in combination with an ECC system can correct additional errors, both hard and soft.

		5	9	
1st write	0000000000000000	110011		original data
1st read	0000010001000000	110011		2 errors
D → \bar{D}	1111101110111111	001100		complement
2nd write	1111101110111111	001100		
2nd read	1111101111111111	001100		hard error fixed
\bar{D} → D	0000010000000000	110011		complement
		000010		new check bits
			110001	syndromes for bit 5

Fig 8 Correction of hard and soft errors. In the case of data word with one hard and one soft error, double complement method has corrected hard error and determined existence of soft error, which is then located by syndrome word and can be corrected

The check bits, or partial word parity bits, generated by modified Hamming codes and the code used in the DP8400, are also capable of providing complete error reporting. Since the single error reporting syndrome words contain an odd number of 1s and the total number of 1s is greater than one, 2-bit errors can easily be distinguished from a 1-bit or detectable triple-bit error. The DP8400 monolithic ECC device performs this error determination by counting the number of 1s in the error indicating syndrome words. When no error exists, the syndrome word contains no 1s, and when a single check is in error, a single 1 is present in the syndrome word. When an odd number of data bits are in error, the number of 1s in the syndrome word is odd and greater than 1 (3 or 5 in this example); if an even number of bits are in error, the syndrome word contains an even number of 1s greater than 0 (2, 4, or 6).

An ECC system implemented with the DP8400 can, at minimum, detect 100% of 2-bit errors; all of these errors are correctable if no more than one of them is soft. The device has complement write and read modes to allow the double complement correct technique to be used with no additional hardware, and other ECC devices can be used with additional components to implement the function.

In Fig 8, a soft error exists in location 5 and a hard error in location 9. During a memory read, the generated

The matrix or code is...a check bit generator for data, but a syndrome generator for error locations.

syndromes are the XOR of the single error that indicates syndrome words representing the error locations. $110001 (+) 001011 = 111010$ [31 (+) 0B = 3A HEX]. Since a double error is indicated—an even number of 1s in the syndrome word—the data and check bits are complemented and placed in the output registers for presentation to the memory. After the memory write and subsequent read, the new data are complemented and stored in the data input latch. The error in location 5 remains in the data. A new set of check bits is generated from the data in the data input latch and compared with that in the check bit input latch, producing the syndrome word 110001 (31 HEX), which corrects the remaining error.

A detected double-bit error followed by a double complement correct cycle is properly reported as to initial error type. If the detected errors were both soft, for example, no change would occur in the data or check bit, and the ECC device error flags would again report a double-bit error. If, after the second read and complement, the error flags still report a single-bit error, the hard error (of a hard and soft combination) has been corrected and only the soft error remains. Of course, the single remaining error will be corrected in the normal manner by the ECC device. In the case of a double hard error, the error flags will report a no-error condition following the second read cycle, indicating that both errors were corrected and that the data are valid.



SIMPLIFICATION OF 2-BIT ERROR CORRECTION

Bit by bit, errors can be detected and eliminated through the use of an error matrix

by Bob Nelson

A computer-generated code, which generally obeys the rules attributed to the Hamming code and many of its variations, can be used to extend error detection and error correcting efficiency in an error checking and correction system. Such a code has been implemented by National Semiconductor on the DP8400, an expandable error checking and correction device packaged in a 48-pin dual inline package. The DP8400 can be used in a minimum hardware implementation of a 2-bit error correction system which will serve as an introduction to the rotational syndrome word generator, and also lead the way to expanding the error correcting capabilities even further.

Syndrome words

The code used in an error checking and correction (ECC) system designed to correct 1-bit errors and detect 2-bit errors for 16-bit data words may be viewed as a 16 x 6 matrix (Fig 1). The matrix describes the error locations and the syndrome bit positions so that the upper left bit of the matrix defines the least significant bit (LSB) for both the error locations and the syndrome bit locations. Each vertical column of the matrix contains the syndrome word (syndrome bits) for that error location in

the data word. For any number of errors, the syndrome word generated by presenting the data word to the matrix is the exclusive OR (XOR) of the syndrome words defined by the error positions. To correct an error, the location of the error must be uniquely identified, and thus the 16 vertical columns must each be unique. A modified Hamming code generates a unique syndrome word for every possible data bit error location and hence may be referred to as a syndrome word generator.

Using syndrome words containing an odd number of 1s is the most common "modification," to the Hamming code. By ensuring that the syndrome words (vertical columns in the matrix) contain either three or five 1s, all applicable error conditions may be defined by counting the syndromes. The absence of a syndrome (ie, a syndrome containing all 0s and no 1s) indicates no error; an odd number greater than one (3 or 5 in this case) defines the location of a single-bit error. Any simultaneous double error will provide a syndrome word containing an even number of 1s greater than zero, while a single 1 in the syndrome word is indicative of a failure in the check bit portion of memory.

The rotational syndrome word generator described here also contains an odd number of 1s in each syndrome word. One additional characteristic common to both the Hamming code and most of its modified versions is that byte parity is an integral part of the matrix itself. However, the code implemented in the DP8400 ECC device and discussed here does not consider byte parity, or word parity, as a part of the code itself.

A 2-bit error correction system may be implemented in either of two ways. A code designed to allow 2-bit error correction may be used, or an existing single-bit error correct code may be extended by adding a second, different code which will ensure that each syndrome

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0	1	2	3	4	5	6	7	8	9	0	1	2	3	4	5		1	1	1	1	1
LSB										error locations					MSB						
0	0	1	1	1	1	1	1	0	1	1	1	0	1	1	1	1	LSB	0			
0	0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	1	1				
1	0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	1	2				
0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	1	3				
1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	1	4				
1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	1	5				
										syndrome words					MSB						

Fig 1 DP8400 generates unique syndrome word to indicate single-bit error position. Generated syndrome word containing all 0s means there is no error in data word.

word generated for any two error locations will be unique. Thus, a secondary, and different, 16 x 6 matrix connected to the primary matrix to form a 16 x 12 matrix will allow double-bit error correction if the XOR of the two 12-bit syndrome words produces a unique word for any two error locations.

Second matrix

The definition of an ECC matrix requires specifying a correspondence between error locations and syndrome words that defines the error location for each set of single-error syndromes. If a matrix is resequenced such that any error location corresponds to a syndrome word different from the original (primary) matrix, a second matrix has been created. For a 16-bit ECC matrix, 16!, or 2.092279 x 10^13, different codes exist. If a second code exists such that when it is combined with the first code (each containing the same syndrome words, but in a different sequence), a unique, larger syndrome word is generated for any two error locations, then an expandable code has been created (Fig 2).

The matrix, or code, used in the DP8400 device is defined such that if a second matrix, identical to the first but shifted by one bit position, is combined with the first, it would form just such a larger matrix. This matrix is fully rotational in that the secondary matrix need only be rotated, or shifted one error bit position to the left or right with respect to the primary matrix, to form larger, unique syndrome words regardless of the assigned correspondence of the primary matrix.

0	1	2	3	4	5	6	7	8	9	0	1	2	3	4	5		1	1	1	1	1
LSB										error locations					MSB						
0	0	1	1	1	1	1	1	0	1	1	1	0	1	1	1	1	LSB	0			
0	0	0	1	0	0	1	0	1	0	1	0	1	1	1	1	1	1				
1	0	0	1	1	0	0	0	1	0	1	0	1	0	1	1	1	2				
0	1	1	0	0	0	0	1	1	1	1	0	1	0	1	1	1	3				
1	1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	1	4				
1	1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	1	5				
0	1	1	1	1	1	0	1	1	1	0	1	1	1	0	1	1	6				
0	0	1	0	0	1	0	1	1	0	1	0	1	1	1	0	1	7				
0	0	1	1	0	0	0	1	0	1	0	1	1	1	1	1	1	8				
1	1	0	0	0	1	1	1	1	0	1	0	1	0	1	1	0	9				
1	0	0	0	1	0	1	1	0	0	1	0	1	0	1	1	1	10				
1	1	0	1	1	1	0	1	0	0	0	1	1	1	0	1	1	MSB	11			
										syndrome words											

Fig 2 Code in DP8400 can be expanded by adding second device with code shifted by one bit position. Note that bottom six bits of each column are identical to top six bits in column to immediate right.

Implementation of this code in the DP8400 allows the data word size to be extended beyond 80 bits, using one device for each additional 16-bit word or portion thereof. The code function as a rotational syndrome word generator exists for all these defined word widths (Fig 3).

In addition to the rotational syndrome word generator, the DP8400 has two important features that permit an easy implementation of a 2-bit error correction system. During a memory read, the error indicating syndromes can be accessed directly by outputting them to the syndrome input/output (I/O) ports; syndrome can also be presented to the syndrome I/O ports to be XORed with the internally generated syndromes inside the DP8400. The internal syndrome decoder is provided with the result.

Error locations	→	0 and 1
produce		
HEX syndrome word	→	E34 (+) A78 = 44C
but		
Error locations	→	2 and 4
produce		
HEX syndrome word	→	1E9 (+) C65 = D8C

Fig 3 Unique syndrome is produced for each pair of error locations which is XOR of the locations. That syndrome can be decoded to identify pair in error.

If, for example, the internally generated 2-bit error syndromes are XORed with externally provided syndromes, representing one of the bits in error, the resulting syndromes representing the unknown error will be presented to the internal syndrome decoder. Once the unknown error is corrected, the data can be output to the data bus. The apparently correct data return zero syndromes (those containing all 0s) which, when XORed with the syndromes being injected, produce the syndromes representing the unknown error and present them to the syndrome decoder. This second error can then be corrected.

Using syndrome words containing an odd number of 1s is the most common "modification" to the Hamming code.

As described, the DP8400 is implemented for a 16-bit system. This "primary" ECC device will provide at its syndrome I/O pins the primary, or least significant six, syndrome bits of an extended matrix ECC system. A "secondary" ECC device is interfaced to the memory system with the data pin-to-system data bit correspondence rotated by one bit position, thus producing the extended matrix just described. The second device requires a second set of check bits; these secondary, or most significant six, syndrome bits are provided by the second DP8400.

The resulting 12-bit syndrome word can be externally decoded to provide the syndromes to be injected to effect 2-bit error correction. In system use, the externally decoded syndromes will be stored in a register. After the syndrome I/O port of the primary ECC device has been "turned around," the register outputs are enabled to allow syndrome injection.

Each of the DP8400 devices provides a set of error flags. Since each device maintains an independent check bit field in memory, errors occurring within a given check bit field are easily and quickly determined. If the errors, regardless of number, are confined solely to the check bit field of one of the devices, a no-error condition will be indicated.

The syndrome word generated by this system is unique for any combination of 2-bit data errors; both devices see an even number, greater than zero, of 1s in the syndrome word (Fig 4). For 2-bit errors involving one data bit and one check bit in either the primary or secondary check bit fields, the DP8400s report an even, greater than zero, and odd number of 1s in the syndromes; again, the syndromes are unique. The remaining type of 2-bit error, that in which both errors occur in either the

Location/Error	Syndromes	Location/Error	Syndromes
Data Sec Prim	Sec Prim	Data Sec Prim	Sec Prim
2 0 0	even even	1 0 1	odd even
1 1 1	even even	2 1 0	odd even
1 0 0	odd odd	0 1 2	odd even
0 1 1	odd odd	1 1 0	even odd
3 0 0	odd odd	2 0 1	even odd
1 0 2	odd odd	0 2 1	even odd
1 2 0	odd odd		

Fig 4 Number and type of errors can be determined by looking at combination of even or odd numbers of 1s in the primary and secondary check bit fields.

primary or secondary check bit fields, produces its own unique syndrome word. However, since one DP8400 reports an even number of 1s in its syndrome word and the other reports all 0s, the data are known to be valid. In addition, in this particular 2-bit error correct system, nearly half of the 3-bit errors result in unique syndrome words and are therefore correctable as well.

Decoding the syndromes

A programmable read only memory (PROM) or electrically programmable read only memory (EPROM) is required as an external syndrome decoder for this 2-bit error correction system. The PROM address inputs are provided by the 12 syndrome bits generated by the two ECC devices. The least significant six bits of the PROM output byte provide, when required, the syndrome bits for subsequent injection into the primary DP8400. The remaining two bits of the PROM output byte provide flags defining the type of error and the contents of the six LSBs of the PROM output byte [Fig 5(a)].

The DP8400's error flags provide initial error determination; if an error that is not a single-bit error occurs, the external syndrome decoder will provide further error determination. Some types of error do not require syndrome injection and are referred to as "zero-pass" correctable errors. An example of such an error is one with a data bit and a secondary check bit in error. This type of error is corrected by the primary ECC device. An error type that requires "one-pass" correction is one with two data bits in error. In this case, syndromes representing a known error are injected into the DP8400,

allowing correction of the unknown error. The remaining single error is then corrected.

The remaining error type, the "two-pass" error, can sometimes be a correctable 3-bit error. The syndromes representing a 2-bit error condition are injected, allowing correction of one error. The remaining 2-bit error produces a new set of syndromes which requires external (second-pass) decoding to produce a set of

MSB	7	6	5	4	3	2	1	0	LSB	
0	0	X	X	X	X	X	X	X		1 pass correctable
0	1	X	X	X	X	X	X	X		2 pass correctable
0	X	X	X	X	X	X	X	X		bits 0 to 5 = syndromes
1	0	X	X	X	X	X	X	X		not correctable
1	1	X	X	X	X	X	X	X		0 pass correctable
1	X	X	X	X	X	X	X	X		bits 0 to 5 <> syndromes

(a)

MSB	7	6	5	4	3	2	1	0	LSB	
1	X	X	X	X	X	X	1	X		primary check bit(s) in error
1	X	X	X	X	X	1	X	X		secondary check bit(s) in error
1	X	X	X	X	1	X	X	X		data bit(s) in error
1	X	X	0	0	X	X	X	X		1 bit in error
1	X	X	0	1	X	X	X	X		2 bits in error
1	X	X	1	0	X	X	X	X		3 bits in error
1	X	X	1	1	X	X	X	X		4 or more bits in error
1	1	0	X	X	X	X	X	X		output data from secondary ECC
1	1	1	X	X	X	X	X	X		output data from primary ECC

(b)

Fig 5 When a PROM is used as external syndrome decoder, its output byte can supply additional data about the error and how it is to be most efficiently corrected.

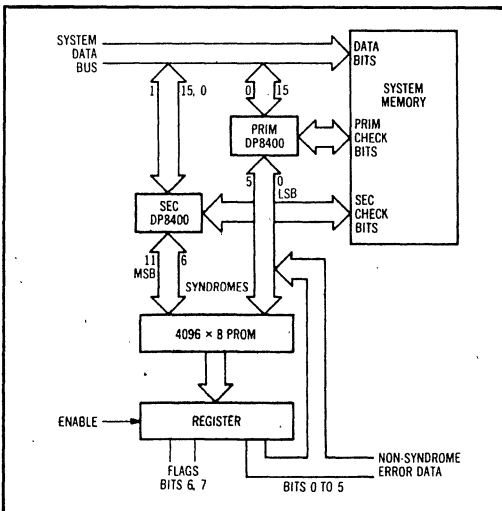


Fig 6 A 2-bit ECC system can be implemented with two DP8400s, a 4k-byte PROM for external syndrome decoding, and a register for temporary storage of syndromes error data. Note that the altered sequence of the lines from the secondary DP8400 reflects the bit rotation needed to expand the unique matrix.

Simplification of 2-Bit Error Correction

```

3000 '*****
3010 '*** 'DC16AROM.BAS' Bob Nelson - Sunnyvale CA - 9/15/81 ***
3020 '*** This program generates the syndrome decoder ROM code for ***
3030 '*** use in implementing a primary syndrome injection two bit ***
3040 '*** correction code generated by a single bit left rotation ***
3050 '*** of the secondary matrix. The primary is a Rotational ***
3060 '*** Syndrome Generator as defined by National Semiconductor ***
3070 '*** in the DP8400. The LPRINT routine may be replaced with a ***
3080 '*** FILE generator or OUPF routine to facilitate the use of a ***
3090 '*** PROM/EPROM programmer..... ***
3100 '*****
3110 '
3120 DEFINT A-Z:DIM SYND(16), PRI(16), ROM(4096,1)
3130 READ A:B=A:FOR C=0 TO 14:READ D:SYND(C)=D*64+A:PRI(C)=A:A=D
3140 NEXT:SYND(15)=B*64+A:PRI(15)=D
3150 DATA 52,56,41,7,37,49,35,25,62,11,13,19,44,55,47,31: 'NSC 80F/2 MATRIX
3160 ROM(0,1)=224:FOR A=1 TO 4095:ROM(A,1)=184:NEXT
3170 FOR A=0 TO 13:FOR B=A+1 TO 14:FOR C=B+1 TO 15 '300 - 560
3180 AD=SYND(A) XOR SYND(B) XOR SYND(C):AE=PRI(A) XOR PRI(B)
3190 IF ROM(AD,1)=184 THEN ROM(AD,1)=AE+64 ELSE ROM(AD,1)=183
3200 NEXT:NEXT:NEXT
3210 FOR A=0 TO 14:FOR B=A+1 TO 15 '200 - 120
3220 AD=SYND(A) XOR SYND(B):ROM(AD,1)=PRI(A)
3230 FOR C=0 TO 5:P=2^C '201 - 720
3240 IF (AD AND P)=0 THEN AE=AD+P ELSE AE=AD-P
3250 IF (PRI(A) AND P)=0 THEN AF=PRI(A)+P+64 ELSE AF=PRI(A)-P+64
3260 IF ROM(AE,1)=184 THEN ROM(AE,1)=AF ELSE ROM(AE,1)=183
3270 NEXT
3280 FOR C=0 TO 5:S=64*2^C '210 - 720
3290 IF (AD AND S)=0 THEN AE=AD+S ELSE AE=AD-S
3300 IF ROM(AE,1)=184 THEN ROM(AE,1)=PRI(A) ELSE ROM(AE,1)=183
3310 NEXT:NEXT:NEXT
3320 FOR A=0 TO 15:AD=SYND(A):ROM(AD,1)=228 '100 - 16
3330 FOR B=0 TO 5:P=2^B '101 - 96
3340 IF (AD AND P)=0 THEN AE=AD+P ELSE AE=AD-P
3350 ROM(AE,1)=205
3360 FOR C=B+1 TO 5:P=2^C '102 - 240
3370 IF (AE AND P)=0 THEN AF=AE+P ELSE AF=AE-P
3380 IF ROM(AF,1)=184 THEN ROM(AF,1)=213 ELSE ROM(AF,1)=183
3390 NEXT:NEXT
3400 FOR B=0 TO 5:S=64*2^B '110 - 96
3410 IF (AD AND S)=0 THEN AE=AD+S ELSE AE=AD-S
3420 ROM(AE,1)=238
3430 FOR C=B+1 TO 5:S=64*2^C '120 - 240
3440 IF (AE AND S)=0 THEN AF=AE+S ELSE AF=AE-S
3450 IF ROM(AF,1)=184 THEN ROM(AF,1)=245 ELSE ROM(AF,1)=183
3460 NEXT:NEXT
3470 FOR B=0 TO 5:P=2^B:FOR C=0 TO 5:S=64*2^C '111 - 596
3480 IF (AD AND P)=0 THEN AE=AD+P ELSE AE=AD-P
3490 IF (AD AND S)=0 THEN AE=AE+S ELSE AE=AE-S
3500 FOR D=0 TO 5:E=2^D
3510 IF ROM(AE,1)=D THEN ROM(AE,1)=183:GOTO 3540
3520 IF ROM(AE,1)=184 THEN ROM(AE,1)=P
3530 NEXT D
3540 NEXT C:NEXT B:NEXT A
3550 FOR A=0 TO 5:FOR B=0 TO 5 '011 - 36
3560 AD=2^A+64*2^B:ROM(AD,1)=235
3570 FOR C=A+1 TO 5:AE=AD+2^C '012 - 90
3580 IF ROM(AE,1)=184 THEN ROM(AE,1)=243 ELSE ROM(AE,1)=183
3590 NEXT
3600 FOR C=B+1 TO 5:AE=AD+64*2^C '021 - 90
3610 IF ROM(AE,1)=184 THEN ROM(AE,1)=243 ELSE ROM(AE,1)=183
3620 NEXT:NEXT:NEXT
3630 FOR A=0 TO 5:AD=2^A:ROM(AD,1)=225 '001 - 6
3640 FOR B=A+1 TO 5:AE=AD+2^B:ROM(AE,1)=233 '002 - 15
3650 FOR C=B+1 TO 5:AF=AE+2^C '003 - 20
3660 IF ROM(AF,1)=184 THEN ROM(AF,1)=241
3670 NEXT:NEXT:NEXT
3680 FOR A=0 TO 5:AD=64*2^A:ROM(AD,1)=226 '010 - 6
3690 FOR B=A+1 TO 5:AE=AD+64*2^B:ROM(AE,1)=234 '020 - 15
3700 FOR C=B+1 TO 5:AF=AE+64*2^C '030 - 20
3710 IF ROM(AF,1)=184 THEN ROM(AF,1)=242
3720 NEXT:NEXT:NEXT
3730 B=0:C=0:FOR A=0 TO 4095:H$=HEX$(ROM(A,1)): 'LPRINT ARRAY
3740 B=B+1:C=C+1:IF LEN(H$)=1 THEN H$="0"+H$
3750 LPRINT USING "\ \";H$:IF C>16 THEN 3770
3760 C=0:LPRINT" ";HEX$(A)
3770 IF B>256 THEN 3790
3780 B=0:LPRINT:LPRINT
3790 NEXT

```

```

1000 *****
1010 **** 'DC16AMAP.BAS' Bob Nelson - Sunnyvale CA - 9/15/81 ***
1020 **** This program generates the syndrome maps for a primary ***
1030 **** syndrome injection implementation of a 16 bit word two ***
1040 **** bit error correct system utilizing a Rotational Syndrome ***
1050 **** Word Generator as implemented in the DP8400 by National ***
1060 **** Semiconductor. These maps are based on single bit left ***
1070 **** rotation of the secondary matrix. The 'c' and 'd' notes ***
1080 **** in the maps denote non-correctable and non-detectable ***
1090 **** three bit error conditions.....
1100 *****
1110 '
1120 DEFINT A-Z:DIM SYND(16),PRI(16),ROM(1132,1):PS="PRIMARY":SS="SECONDARY"
1130 READ A:B=A:FOR C=0 TO 14:READ D:SYND(C)=D*64+A:PRI(C)=A:A=D
1140 NEXT:SYND(15)=B*64+A:PRI(15)=D
1150 DATA 52,56,41,7,37,49,35,25,62,11,13,19,44,55,47,31: 'NSC 80F/2 MATRIX
1160 LPRINT "ONE DATA ERROR SYNDROME MAP":LPRINT
1170 FOR A=0 TO 15:LPRINT USING"##";A;:LPRINT" ";:NEXT:LPRINT:LPRINT
1180 FOR A=0 TO 15:LPRINT HEX$(SYND(A));" ";:NEXT:LPRINT
1190 FOR A=1 TO 4:LPRINT:NEXT
1200 LPRINT"TWO DATA ERROR CORRECT SYNDROME MAP":LPRINT
1210 FOR A=1 TO 15:LPRINT USING"##";A;:LPRINT" ";:NEXT:LPRINT:LPRINT
1220 FOR A=0 TO 14:FOR B=A+1 TO 15:AD=SYND(A) XOR SYND(B) '200 - 120
1230 ROM(X,1)=AD:H$=HEX$(AD):IF LEN(H$)=2 THEN H$="0"+H$
1240 LPRINT H$;" ";:X=X+1:NEXT B:LPRINT USING"###";A
1250 LPRINT TAB((A+1)*5+1);:NEXT A:FOR A=1 TO 4:LPRINT:NEXT
1260 FOR A=0 TO 5:S=64*2^A:FOR B=0 TO 5:P=2^B:FOR C=0 TO 15 '111 - 576
1270 AD=SYND(C):IF (AD AND P)=0 THEN AD=AD+P ELSE AD=AD-P
1280 IF (AD AND S)=0 THEN AD=AD+S ELSE AD=AD-S
1290 ROM(X,1)=AD:X=X+1:NEXT:NEXT:NEXT:A$=" "
1300 LPRINT"ONE DATA, ONE PRI, ONE SEC CHECK ERROR SYNDROME MAPS":LPRINT
1310 LPRINT:X=120:FOR A=0 TO 5:LPRINT"SECONDARY CHECK BIT";A:LPRINT
1320 FOR F=0 TO 15:LPRINT USING"##";F;:LPRINT" ";:NEXT F:LPRINT:LPRINT
1330 FOR B=0 TO 5:FOR C=0 TO 15:FOR E=0 TO 119
1340 IF ROM(E,1)=ROM(X,1) THEN A$="d":EO=EO+1:GOTO 1370 ELSE NEXT E
1350 FOR D=120 TO 695:IF D=X THEN D=D+1
1360 IF ROM(D,1)=ROM(X,1) THEN A$="c":E2=E2+1 ELSE NEXT D
1370 H$=HEX$(ROM(X,1)):IF LEN(H$)=2 THEN H$="0"+H$
1380 LPRINT H$;A$;:X=X+1:A$=" ":NEXT C:LPRINT USING"####";B
1390 NEXT B:LPRINT:LPRINT:NEXT A
1400 LPRINT"576 ONE DATA, ONE PRI, ONE SEC CHECK errors are possible."
1410 LPRINT EO;"TWO DATA errors are not detectable.":LPRINT E2;
1420 LPRINT "ONE DATA, ONE PRI, ONE SEC CHECK errors are not correctable."
1430 LPRINT 100*((576-EO)/576);"PERCENT DETECT - ";
1440 LPRINT 100*((576-EO-E2)/576);"PERCENT CORRECT"
1450 FOR A=1 TO 4:LPRINT:NEXT:EA=EO:EO=0:EC=E2:E2=0
1460 X=0:FOR A=0 TO 15:AD=SYND(A):ROM(X,1)=AD:X=X+1:NEXT '100 - 16
1470 FOR A=0 TO 5:P=2^A:FOR B=0 TO 5:S=64*2^B '011 - 36
1480 AD=P+S:ROM(X,1)=AD:X=X+1:NEXT:NEXT
1490 FOR A=0 TO 15:FOR B=A+1 TO 15:FOR C=B+1 TO 15 '300 - 560
1500 AD=SYND(A) XOR SYND(B) XOR SYND(C)
1510 ROM(X,1)=AD:X=X+1:NEXT:NEXT:NEXT
1520 FOR A=0 TO 5:P0=2^A:FOR B=A+1 TO 5:P1=2^B '102 - 240
1530 FOR C=0 TO 15:AD=SYND(C):IF (AD AND P0)=0 THEN AD=AD+P0 ELSE AD=AD-P0
1540 IF (AD AND P1)=0 THEN AD=AD+P1 ELSE AD=AD-P1
1550 ROM(X,1)=AD:X=X+1:NEXT:NEXT:NEXT
1560 FOR A=0 TO 5:S0=64*2^A:FOR B=A+1 TO 5:S1=64*2^B '120 - 240
1570 FOR C=0 TO 15:AD=SYND(C):IF (AD AND S0)=0 THEN AD=AD+S0 ELSE AD=AD-S0
1580 IF (AD AND S1)=0 THEN AD=AD+S1 ELSE AD=AD-S1
1590 ROM(X,1)=AD:X=X+1:NEXT:NEXT:NEXT
1600 LPRINT"THREE DATA BIT ERROR SYNDROME MAPS":LPRINT:LPRINT
1610 X=52:A$=" ":FOR A=0 TO 13:LPRINT"DATA bit";A:LPRINT
1620 FOR D=A+2 TO 15:LPRINT USING"##";D;:LPRINT" ";:NEXT:LPRINT:LPRINT
1630 FOR B=A+1 TO 14:FOR C=B+1 TO 15:FOR E=16 TO 51
1640 IF ROM(E,1)=ROM(X,1) THEN A$="d ":EO=EO+1:GOTO 1690 ELSE NEXT E
1650 FOR F=612 TO 1091
1660 IF ROM(F,1)=ROM(X,1) THEN A$="c ":E1=E1+1:GOTO 1690 ELSE NEXT F
1670 FOR G=52 TO 611:IF G=X THEN G=G+1
1680 IF ROM(G,1)=ROM(X,1) THEN A$="c ":E2=E2+1 ELSE NEXT G
1690 H$=HEX$(ROM(X,1)):IF LEN(H$)=2 THEN H$="0"+H$
1700 LPRINT H$;A$;:X=X+1:A$=" ":NEXT C:LPRINT USING"###";B
1710 LPRINT TAB((B-A)*5+1);:NEXT B:LPRINT:LPRINT:NEXT A
1720 LPRINT"560 THREE DATA BIT errors are possible.":LPRINT EO;
1730 LPRINT"ONE PRI, ONE SEC CHECK errors are not detectable.":LPRINT E1;
1740 LPRINT"ONE DATA, TWO PRI or TWO SEC CHECK errors are not correctable."
1750 LPRINT E2;"THREE DATA BIT errors are not correctable."
1760 LPRINT 100*((560-EO)/560);"PERCENT DETECT - ";
1770 LPRINT 100*((560-EO-E1-E2)/560);"PERCENT CORRECT"
1780 FOR A=1 TO 4:LPRINT:NEXT A:EA=EA+EO:EB=EB+E1:EC=EC+E2
1790 LPRINT"ONE DATA, TWO PRIMARY CHECK ERROR SYNDROME MAPS":LPRINT:LPRINT
1800 A$=" ":EO=0:E1=0:E2=0:FOR A=0 TO 4:LPRINT"PRIMARY check bit";A:LPRINT
1810 FOR F=0 TO 15:LPRINT USING"##";F;:LPRINT" ";:NEXT F:LPRINT:LPRINT
1820 FOR B=A+1 TO 5:FOR C=0 TO 15:FOR E=852 TO 1091

```

```

1830 FOR F=52 TO 611
1840 IF ROM(F,1)=ROM(X,1) THEN A$="c":E2=E2+1:GOTO 1860 ELSE NEXT F
1850 IF ROM(E,1)=ROM(X,1) THEN A$="c":E1=E1+1 ELSE NEXT E
1860 H$=HEX$(ROM(X,1)):IF LEN(H$)=2 THEN H$="0"+H$
1870 LPRINT H$;A$;X=X+1:A$=" ":NEXT C:LPRINT USING "####";B
1880 NEXT B:LPRINT:LPRINT:NEXT A
1890 LPRINT"240 ONE DATA, TWO PRIMARY CHECK errors are possible."
1900 LPRINT E1;"ONE DATA, TWO SECONDARY CHECK errors are not correctable."
1910 LPRINT E2;"THREE DATA BIT errors are not correctable."
1920 LPRINT"100 PERCENT DETECT - ";100*((240-E1-E2)/240);"PERCENT CORRECT"
1930 FOR A=1 TO 4:LPRINT:NEXT A:EB=EB+E1+E2:E1=0:E2=0
1940 LPRINT"ONE DATA, TWO SECONDARY CHECK ERROR SYNDROME MAPS":LPRINT
1950 LPRINT:FOR A=0 TO 4:LPRINT"SECONDARY check bit";A:LPRINT
1960 FOR F=0 TO 15:LPRINT USING "##";F;LPRINT " ";NEXT F:LPRINT:LPRINT
1970 FOR B=A+1 TO 5:FOR C=0 TO 15:FOR E=612 TO 851
1980 FOR F=52 TO 611
1990 IF ROM(F,1)=ROM(X,1) THEN A$="c":E2=E2+1:GOTO 2010 ELSE NEXT F
2000 IF ROM(E,1)=ROM(X,1) THEN A$="c":E1=E1+1 ELSE NEXT E
2010 H$=HEX$(ROM(X,1)):IF LEN(H$)=2 THEN H$="0"+H$
2020 LPRINT H$;A$;X=X+1:A$=" ":NEXT C:LPRINT USING "####";B
2030 NEXT B:LPRINT:LPRINT:NEXT A
2040 LPRINT"240 ONE DATA, TWO SECONDARY CHECK errors are possible."
2050 LPRINT E1;"ONE DATA, TWO PRIMARY CHECK errors are not correctable."
2060 LPRINT E2;"THREE DATA BIT errors are not correctable."
2070 LPRINT"100 PERCENT DETECT - ";100*((240-E1-E2)/240);"PERCENT CORRECT"
2080 FOR A=1 TO 4:LPRINT:NEXT A:EB=EB+E1+E2:A$=" ":C0=1:C1=64
2090 IF W=1 THEN P$="SECONDARY":S$="PRIMARY":C0=64:C1=1
2100 X=0:FOR A=0 TO 15:AD=SYND(A):FOR B=0 TO 5:P=C0*2^A '101/110 - 96
2105 IF (AD AND P)=0 THEN AE=AD+P ELSE AE=AD-P
2110 ROM(X,1)=AE:X=X+1:NEXT B:NEXT A
2120 FOR A=0 TO 5:S=C1*2^A:FOR B=0 TO 15:FOR C=B+1 TO 15 '210/201 - 720
2130 AD=SYND(B) XOR SYND(C):IF (AD AND S)=0 THEN AE=AD+S ELSE AE=AD-S
2140 ROM(X,1)=AE:X=X+1:NEXT C:NEXT B:NEXT A
2150 FOR A=0 TO 5:AD=C1*2^A:FOR B=0 TO 4:AE=AD+C0*2^B '012/021 - 90
2160 FOR C=B+1 TO 5:ROM(X,1)=AE+C0*2^C:X=X+1:NEXT:NEXT:NEXT
2170 A$=" ":LPRINT"TWO DATA, ONE ":LPRINT S$;
2180 LPRINT" CHECK ERROR SYNDROME MAPS":LPRINT:LPRINT
2190 X=96:E0=0:E1=0:E2=0:FOR A=0 TO 5:LPRINT S$;
2200 LPRINT" check bit";A:LPRINT
2210 FOR F=1 TO 15:LPRINT USING"##";F;LPRINT " ";NEXT F:LPRINT:LPRINT
2220 FOR B=0 TO 14:FOR C=B+1 TO 15;FOR D=0 TO 95
2230 IF ROM(D,1)=ROM(X,1) THEN A$="d ":E0=E0+1:GOTO 2280 ELSE NEXT D
2240 FOR G=96 TO 815:IF G=X THEN G=G+1
2250 IF ROM(G,1)=ROM(X,1) THEN A$="c ":E2=E2+1:GOTO 2280 ELSE NEXT G
2260 FOR E=816 TO 905
2270 IF ROM(E,1)=ROM(X,1) THEN A$="c ":E1=E1+1 ELSE NEXT E
2280 H$=HEX$(ROM(X,1)):IF LEN(H$)=2 THEN H$="0"+H$
2290 LPRINT H$;A$;X=X+1:A$=" ":NEXT C:LPRINT USING"####";B
2300 LPRINT TAB((B+1)*5+1);:NEXT B:LPRINT:LPRINT:NEXT A
2310 LPRINT"720 TWO DATA, ONE ":LPRINT MID$(S$,1,3);
2320 LPRINT" CHECK errors are possible."
2330 LPRINT E0;"ONE DATA, ONE ":LPRINT MID$(P$,1,3);
2340 LPRINT" CHECK errors are not detectable.":LPRINT E1;"TWO ";
2350 LPRINT MID$(P$,1,3);:LPRINT", ONE ":LPRINT MID$(S$,1,3);
2360 LPRINT" CHECK errors are not correctable."
2370 LPRINT E2;"TWO DATA, ONE ":LPRINT MID$(S$,1,3);
2380 LPRINT" CHECK errors are not correctable."
2390 LPRINT 100*((720-E0)/720);"PERCENT DETECT - ";
2400 LPRINT 100*((720-E0-E1-E2)/720);"PERCENT CORRECT"
2410 FOR A=1 TO 4:LPRINT:NEXT A:EA=EA+E0:EB=EB+E1:EC=EC+E2
2420 LPRINT"TWO ":LPRINT MID$(P$,1,3);:LPRINT", ONE ":LPRINT MID$(S$,1,3);
2430 LPRINT" CHECK ERROR SYNDROME MAPS":LPRINT:LPRINT
2440 X=816:E0=0:E1=0:E2=0:FOR A=0 TO 5:LPRINT S$;
2450 LPRINT" check bit";A:LPRINT
2460 FOR F=1 TO 5:LPRINT USING "##";F;LPRINT " ";NEXT F:LPRINT:LPRINT
2470 FOR B=0 TO 4:FOR C=B+1 TO 5
2480 FOR D=96 TO 815:IF ROM(D,1)=ROM(X,1) THEN A$="c ":E1=E1+1 ELSE NEXT D
2490 H$=HEX$(ROM(X,1)):IF LEN(H$)=2 THEN H$="0"+H$
2500 LPRINT H$;A$;X=X+1:A$=" ":NEXT C:LPRINT USING"##";B
2510 LPRINT TAB((B+1)*5+1);:NEXT B:LPRINT:LPRINT:NEXT A:LPRINT"90 TWO ";
2520 LPRINT MID$(P$,1,3);:LPRINT", ONE ":LPRINT MID$(S$,1,3);
2530 LPRINT" CHECK errors are possible.":LPRINT E1;"TWO DATA, ONE ";
2540 LPRINT MID$(S$,1,3);:LPRINT" CHECK errors are not correctable."
2550 LPRINT"100 PERCENT DETECT - ";100*((90-E1)/90);"PERCENT CORRECT"
2560 FOR A=1 TO 4:LPRINT:NEXT A:EA=EA+E0:EB=EB+E1:EC=EC+E2
2570 IF W=0 THEN W=1:GOTO 2090
2580 FOR A=1 TO 4:LPRINT:NEXT
2590 LPRINT"3290 THREE BIT ERRORS (all types) are possible."
2600 LPRINT EA;"of these errors cannot be detected."
2610 LPRINT EB+EC;"of these errors cannot be located."
2620 LPRINT 100*((3290-EA)/3290);"PERCENT DETECT - ";
2630 LPRINT 100*((3290-EA-EB-EC)/3290);"PERCENT CORRECT"

```

single-bit error syndromes. The error status at this point is that of a "one pass" error, and correction proceeds accordingly.

When a zero-pass error or a noncorrectable error occurs, the six LSBs from the PROM provide additional information. For example, a hexadecimal coded output from the PROM [Fig 5(b)] defines a 2-bit error in which one bit in error is a data bit and the other a primary check bit. The primary ECC device detects a 2-bit error while the secondary device detects only the data bit in

The first of the two programs provided here is called "DC16AROM.BAS," and is a listing in hexadecimal representing the contents of the syndrome decoding PROM. The file may be presented to an output port for loading a PROM programmer if minor program changes are made. The second program, called "DC16AMAP.BAS," generates all the required syndrome maps, which include flags for all correctable 3-bit errors. These programs were written in Microsoft Basic and are compilable.

Some types of error do not require syndrome injection and are referred to as "zero-pass" correctable errors.

error. Bit 5 of the PROM output directs the secondary device to output corrected data to the system. In most cases, bit 5 is a 1, and corrected data are output from the primary ECC device. Bits 0 through 4 of the PROM output define the error type and the number of bits in error (Fig 6) when the MSB (bit 7) is a 1. When the MSB is a 0, syndromes are required for correction, and bits 0 through 5 represent those syndromes.

EFFORTLESS ERROR MANAGEMENT

Basic application of error management techniques is based on error history, including the double complement error correction cycle

by **Bob Nelson**

When implemented only in hardware, error management is generally limited to simple error logging. In most systems, error logging hardware is designed to capture the location of one error and use this information for maintenance purposes. In more sophisticated systems, however, software extends the error management function: after hardware obtains error information, data are accumulated on disk to expand storage capacity for information relating to error locations. Beyond the error information storage function of error management, which is useful for maintenance, some systems implement a correction procedure based on error history. If two errors occur in a memory word where an error has previously occurred, it is likely that both errors can be corrected. The basic error management system described in this article will provide a high correction rate for all 2-bit errors, except when two soft errors simultaneously occur in a memory word with no error history.

Error management system

The error management system comprises the central processing unit (CPU), the system memory, an error checking and correction (ECC) device, and an error management unit (EMU). The CPU is a 16-bit machine

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and requires commensurate memory. Actual memory, including the six check bits that the ECC device requires, is 22 bits wide. The ECC device is based on the DP8400 monolithic ECC unit manufactured by National Semiconductor. The EMU is a hypothetical device that can be implemented in hardware, partially or entirely, depending on system requirements.

The DP8400 provides several functions and features that allow easy implementation of a minimum hardware error management system. Error indicating syndrome words must be available to the EMU directly and syndrome injection capability must exist. (See "Simplification of 2-Bit Error Correction," Jan 1982, pp 127-136, for a discussion of the DP8400's syndrome input/output ports.) The DP8400 also provides the hardware required to perform a double complement correct cycle. Error flags must be provided to discriminate between 2-bit and detectable 3-bit errors; the DP8400 provides three such flags to include this function.

Vertical columns in the matrix shown in Fig 1 represent the single data bit error indicating syndrome words. A double data bit error syndrome word results from exclusive ORing (XOR) the two single-bit error indicating syndrome words that correspond to the bit locations in error. A detectable triple data bit syndrome word is any one of the ten syndrome words, not included as part of the matrix, which contains either three or five 1s. Syndrome words that represent check bit errors contain 1s in the syndrome word bit positions corresponding to the check bits in error, and 0s in the remaining bit positions. An error condition involving the data and check bit fields provides a syndrome word that represents the data bit(s) in error, XORed with a syndrome word representing the check bit(s) in error.

Error management unit

The EMU is memory intensive and uses memory in the form of an associative stack. Three fields constitute each of the 16 words in the stack: the 8-bit address field, which is the associative portion of the word; the 2-bit

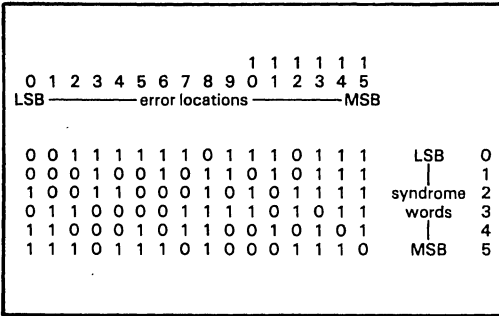


Fig 1 DP8400 syndrome word generator. Presenting errors to unique matrix produces syndrome words.

tag field; and the 6-bit syndrome field (Fig 2). The pointer addresses the stack. The EMU also contains a syndrome comparator, a temporary syndrome register, and a tag bit attribute register and comparator. The EMU monitors most ECC flags and provides flags of its own both to the ECC device and to the CPU; monitoring the memory address and comparing that address to the

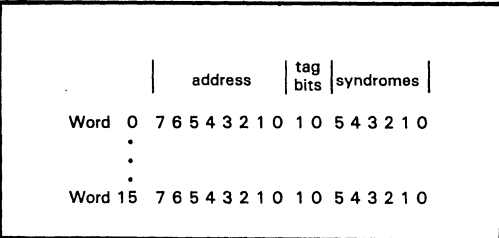


Fig 2 Associative stack organization. Of 16-bit address, eight address bits are most significant bits. Tag bits indicate type of error, and syndrome bits contain syndrome word.

stack's address field is a major function of the EMU. When the "stack full" flag is off, however, the number of words in the match area is limited by the location of the stack pointer. If a match occurs, ie, if the current memory address is an address at which an error occurred previously, the information obtained from the previous error can be used to correct more than one error bit. Each EMU function will be defined in a subsequent section of this article.

Single-bit error: first occurrence

Tag Bits	Information Status
00	soft single-bit error
01	firm single-bit error
10	hard single-bit error
11	hard double-bit error

Fig 3 Tag bit field of stack indicates error type for more efficient processing by error management system. Tag bit field could be extended in other systems to provide more error information.

error in the current address. The error may be in the data bit or check bit field of memory. Error address, tag bits (Fig 3), and single-bit error indicating syndrome word are stored in the EMU stack. Tag bits are assigned a value of 00, indicating a soft single-bit error. The stack pointer is then incremented and the ECC device corrects

the single-bit error in the usual way. Stored syndromes contain an odd number of 1s. In Fig 4, data bit 5 fails at memory address 52 HEX, check bit 3 fails at address 45 HEX, and data bit 9 fails at address C7 HEX. Since the errors have not occurred previously at these addresses, they are given a tag bit value of 00. Logging errors should not impact the speed or function of the ECC system in performing single-bit error correction.

Double-bit error: first occurrence

When a double-bit error occurs at an address with no error history, the EMU exercises the only available option, a double complement correct cycle. As the ECC device enters the complement write mode, the syndrome word that represents the double-bit error condition is stored in the temporary syndrome register. Then the ECC system performs a double complement correct cycle to generate a second set of error flags. If two soft errors caused the initial indication of a 2-bit error, the second set of error flags will also indicate two errors and represent a noncorrectable condition. Any double-bit error situation other than that of two soft errors will produce error flags that indicate a correctable condition at the conclusion of the double complement correct cycle.

One hard and one soft

Error flags produced after the second complement of the double complement correct cycle indicate a single error if the initial error condition was one hard and one soft. At that point, the hard error will have been "corrected" and the remaining soft error indicated. The ECC device will generate a new single-bit error indicating syndrome word, which the EMU will XOR with the previously stored double-bit error indicating syndrome word. The result, which is the single-bit hard error indicating syndrome word, is stored in the stack.

To identify the bit as a single hard error, the tag bit field is set to a value of 10. After the error information is stored, the stack pointer is incremented. The ECC device corrects the single error in the usual manner. The remaining soft error may be either a check bit error or a data bit error. Fig 5 illustrates a soft error in data bit location 2 and a hard error in data bit location 11. A double complement cycle corrects the error in location 11. Representing the soft error, a new syndrome word is then XORed with the original syndrome word to produce

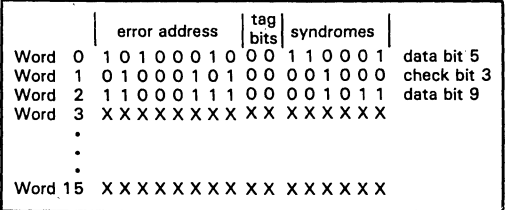


Fig 4 Logging errors on EMU stack. Single-bit errors occurring at addresses with no previous error history receive tag bit value of 00.

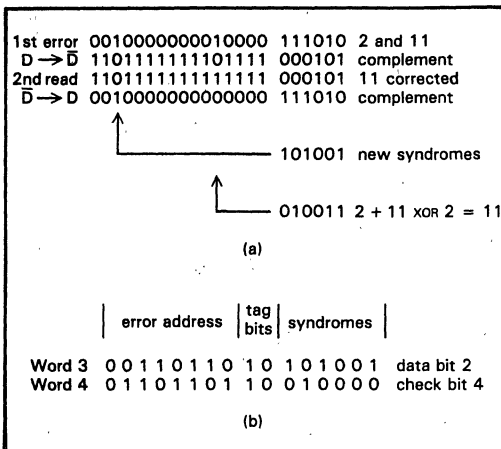


Fig 5 After correcting hard error in bit position 11 (a), system stores hard error syndrome on associative stack (b) and sets tag bit field to indicate single-bit hard error.

	error address	tag bits	syndromes	
Word 0	1 0 1 0 0 0 1 0	0 0	1 1 0 0 0 1	data bit 5
Word 1	0 1 0 0 0 0 1 0	0 0	0 0 1 0 0 0	check bit 3
Word 2	1 1 0 0 0 0 1 1	0 0	0 0 1 0 1 1	data bit 9
Word 3	0 0 1 1 0 1 1 0	1 0	1 0 1 0 1 0	data bit 2
Word 4	0 1 1 0 1 1 0 1	1 0	0 1 0 0 0 0	check bit 4
Word 5	1 0 0 0 0 1 0 0	1 1	1 0 1 0 0 0	2 hard
Word 6	X X X X X X X X	X X	X X X X X X X X	
...				
Word 15	X X X X X X X X	X X	X X X X X X X X	

Fig 6 Contents of EMU's stack containing initial occurrence of each error type.

the syndrome word that represents the hard error. These hard error syndromes are stored as shown in Fig 6, which also shows the storage of a hard check bit error at address 6D HEX.

Two hard

An ECC "no-error" flag, following a double complement correct cycle, indicates an initial error condition of two hard errors. Data following the second complement are correct; since no error exists, a syndrome word of all zeros is generated. The EMU will store the error address, the tag bits, and the contents of the temporary register. Tag bits will be given a value of 11, indicating a double-bit hard error. The stored syndrome word is then XORed with the contents of the temporary syndrome register and the new syndrome word from the ECC device (as with a one soft/one hard error condition), and the stack pointer is incremented. In this example, the information obtained from a double-bit hard error at address 84 HEX, including a syndrome word of 101000, is stored. A 2-bit error indicating syndrome word provides no information regarding the location of the errors. Errors in data bit locations 13 and 15, for example, produce the stored syndrome word as would errors in check bit locations 3 and 5. Fig 6 illustrates the contents of the associative stack portion of the EMU following the first occurrence of each type of error discussed. Word 5 in the stack represents the double-bit hard error.

Logging the errors

As errors occur at new addresses, error data are stored in the stack and the stack pointer is incremented. When information is entered in stack word 15 a "stack full" flag is set. The stack full flag directs the pointer to the lowest word address location in the stack containing the value 00 in the tag bit field. After storing data, the stack pointer goes to the next highest word address location that contains a 00 in the tag bit field. The stack contains the most recent error addresses at which single-bit soft errors occurred and all addresses at which firm or hard errors occurred. When no tag bit field contains 00, the "overflow" flag is provided and no additional stack storage occurs. However, logged error information is available to the system. One of the DP8400 modes, for example, allows data to be provided to the syndrome input/output ports and output through the data input/output ports, a capability that allows the error information to be dumped to the system disk for an additional level of storage. In another mode, the DP8400 can internally transfer data from the data input to the syndrome output, allowing the stack to be loaded from the system disk via the data bus.

Error locations are stored in real time by the logging procedure. Error resolution is defined by the correspondence of the memory address bits to the EMU address inputs. The EMU described here has eight address inputs that allow chip level error resolution in a 1M-byte memory system when 64k-bit dynamic random access memories are used. Since the EMU does not monitor the least significant eight memory address lines, error information—specifically the address and syndromes as stored in the EMU—represents a memory chip location. If a "read error" match occurs, only the tag bits and/or the stored syndrome word may be updated. Therefore, each unique error address can exist in a single stack location. Each stored word location defines one defective bit (chip) location if the syndrome word indicates a single-bit error. In some cases, the error information will represent two hard errors, which normally cannot be located.

Relocating the errors

In response to new error information, it may be desirable to change the error locations as defined by the syndrome words stored in the EMU. If a single-bit error is accompanied by an address match and tag bits representing a stored single-bit soft error, but if the syndrome comparison indicates that a different bit is in error, the

Stored Error	Tags	Detected Error
1 bit, firm	01	1 soft, 1 hard
1 bit, hard	10	1 soft, 1 hard
1 bit, soft	00	1 soft, 1 hard
1 bit, soft	00	2 soft
1 bit, firm	01	2 hard
1 bit, hard	10	2 hard

Fig 7 Errors for syndrome injection in order of probability. Syndrome injection in the DP8400 allows faster correction than double complement method.

syndrome field of the matching stack word should be changed to the new syndrome word. The ECC will correct the single-bit error in the normal manner, and the most recent soft error information for that memory address will be maintained. Previous soft error information can be off-loaded to a secondary storage device prior to the update.

Maintenance help

Maintenance tools are a by-product of the EMU system. During the ECC procedure, error locations are identified and error types determined. EMU generated flags, which are provided when the stack contents reach a defined level, allow the error information to be offloaded to the system disk and the EMU to be cleared and reloaded with selected error information from disk. After the error information is loaded on disk, the system can be powered-down for maintenance. Following system power-up, suspect information about error location may be written to the EMU. This extended logging capability is part of the total error management system.

Redefinition

When a single-bit error occurs in a location at which a single-bit error has occurred previously, and the stored syndrome word is the same as the single-bit error indicating syndrome word generated by the ECC device, it may be necessary to redefine the error type. If the match provides tag information indicating a soft error (tag field = 00), the tag field will be changed to 01 to indicate a single-bit firm error. Such a redefinition is valid. For instance, a firm error may be an unproved hard error or an error-prone memory device sensitive to alpha particles, system noise, or both. Such an error can be treated as either a soft error or a hard error, or be given a definition based on the present error. For the purpose of this discussion, a firm error will be treated as a hard error.

With...double complement correct cycles, 100% of 2-bit errors can be corrected when...one of the errors is hard, regardless of...error history.

Although a soft error can occur in any given location within a chip, a second soft error is most likely to occur within the same chip. Error-prone chips are identified and tagged as firm error locations. In the EMU, both the syndromes and the address field are compared, providing higher error resolution within a word. In this EMU, the tag bit field is updated and the syndrome field is rewritten (if the second error is not in the same chip, the most recent single-bit error location in that word will be stored). The ECC device corrects the single-bit error in the normal manner.

Double-bit error: subsequent occurrence

When a double-bit error occurs and the EMU obtains a match, the contents of the tag bit field dictate the possible courses of action (Fig 7). If the tag bits are 11, for example, a double complement correct cycle is the only option. If the tag bits indicate a single-bit hard error location, a double complement correct cycle could be implemented. On the other hand, it is reasonable to

assume that the stored syndrome word represents one of the two present error locations; in that case the error can be corrected without additional memory cycles.

One hard—one soft, one hard

If a match is obtained, tag bits are 10, and a 2-bit error has been detected, it is most likely that one error is soft and the other hard. Syndrome injection will obtain the fastest correction. The syndrome word in the stack, which usually represents the hard error location, is presented to the DP8400. There it is XORed with the internally generated syndrome word to provide the resulting soft error syndrome word, which is then presented to the syndrome decoder. After the ECC device corrects the soft error, it generates new check bits and zero syndromes. XORing the new syndromes with the still-injected hard error syndrome word, the unit decodes the hard error location and corrects the second error. This procedure allows correction of 2-bit errors without additional memory cycles, once the location of the hard error has been determined. Although a firm error is treated as a hard error, it must be given special consideration during system maintenance.

One soft—one soft, one hard

If a 2-bit error is detected and a match obtained with a tag of 01, the highest probability is that one error is soft and one is hard. The syndrome word from the stack is injected into the DP8400, where it is XORed with the internally generated syndrome word, providing the result to the syndrome decoder. Correcting the soft error, the ECC device generates new check bits and syndromes, XORs the new syndromes with the still-injected hard error syndrome word provided by the EMU, decodes the known error location, and corrects it. When the location of one error has been determined, this procedure allows high speed correction of 2-bit errors without additional memory cycles.

One soft—two soft

If a match is obtained, tag bits are 01, and a 2-bit error is detected, both errors are probably soft and can be corrected by syndrome injection. The syndrome word in the stack (which often represents one of the soft error locations) is presented to the DP8400, where it is XORed with the syndrome word, generated internally to provide the unknown soft error syndrome word to the syndrome decoder. Correcting the soft error, the ECC device generates new check bits and zero syndromes. XORing the new syndromes with the still-injected "known" soft error indicating syndrome word, it decodes the error location and corrects the second error. Thus, two soft errors can be corrected if the location of one is known.

One firm or hard—two hard

If two hard errors occur at an address where a single-bit hard error has been recorded previously, syndrome injection will usually accomplish the correction. The syndrome word in the stack, which most likely represents one of the hard error locations, is presented to the DP8400 where it is XORed with the internally generated syndrome word, providing the result to the syndrome decoder. The ECC device corrects the first error and generates new check bits and zero syndromes. XORing the new syndromes with the still-injected "known"

error indicating syndrome word, the unit corrects the second error. This procedure allows high speed correction of two hard errors when the location of one is known.

Double complement

The double complement error correction cycle is effective for locating hard errors in an error management system. This technique is effective when speed of error correction is of less concern than system integrity. Use

Stored Error	Tags	Detected Error
1 bit, soft	00	2 hard
1 bit, firm	01	2 soft
1 bit, hard	10	2 soft

Fig 8 Errors for double complement correction. When speed is of less priority, double complement method allows more precise error detection, logging, and correction.

of the double complement correct cycle following the detection of every error enhances error determination and correction. Immediate determination of single-bit hard errors improves the possibility that double-bit errors in the same defined address can be corrected. The next level of error detection and correction efficiency, using the double complement correct cycle for each detected error, includes those error types noted in Fig 8.

One soft—two hard

A no-error indication from the ECC device following the double complement correct cycle will complete the definition of the error type—defined as a 2-bit error by the syndrome word stored in the temporary syndrome register—as a 2-bit hard error. If a match occurs but the tag bit field indicates a single-bit soft error, the tag bit field can be changed to 11, indicating two hard errors, and the syndrome field replaced with the contents of the temporary syndrome register. Error information can be offloaded to a secondary storage device before this update.

One firm or hard—two soft

If the ECC device generates error flags indicating a double-bit error at the conclusion of the double complement correct cycle, the 2-bit error that instigated the cycle remains and contains two soft errors. Since the only recorded error at the current memory location is hard, the errors are not recoverable and system operation terminates. In some systems, a firm error may be defined as a soft error, and data may be recovered. When offloading of soft errors is practiced, the disk or other storage mechanism can be interrogated for prior memory errors at the current address. These soft errors can be corrected if proper information is available.

Two hard—double error

When a match occurs and the tag bits indicate that an earlier 2-bit error has been recorded for the present memory address, ECC device's error flags identify the error type after the double complement correct cycle. If the present error is soft, system operation must be terminated—assuming that no additional relevant information regarding errors at this address is available from other sources. If the second set of error flags indicates that the present error is a 2-bit hard error, the errors can be corrected. Comparing the syndrome words in the temporary syndrome register and the stack will provide additional information. If the syndrome words do not match, three or four hard errors exist and system operation must be terminated.

Locating two hard errors

When the presence of two hard errors has been determined, a subsequent access at the same address will most likely indicate a single-bit error. If the single-bit error is in one of the two locations that had defined the previous 2-bit hard error, adequate information is available to locate the other error. The temporary syndrome register will store the single-bit error indicating syndrome word. Data are corrected by the double complement correct cycle, and the syndrome word in the stack can be replaced by the contents of the temporary syndrome register. The double-bit hard error indicating syndrome word can be offloaded and the word replaced. The new word will then be offloaded and XORed with the first syndrome word, keeping the result in the secondary storage element. Secondary storage is available for interrogation if additional errors occur in the same address. In more sophisticated error management systems, additional tag bits are made available in the EMU stack. One of these tag bits can be used to indicate that additional error information exists in secondary storage for that error address.

Summary

The simplified error management system presented here allows correction of double-bit errors if one of the errors has previously occurred. With the use of double complement correct cycles, 100% of 2-bit error correction is provided when at least one of the errors is hard, regardless of previous error history. Enhanced error logging is provided with error type determination capability. Maintenance aids are provided through the DP8400's bidirectional data transfer capability between the syndrome input/output and data input/output ports.

DP84300 Programmable Refresh Timer

General Description

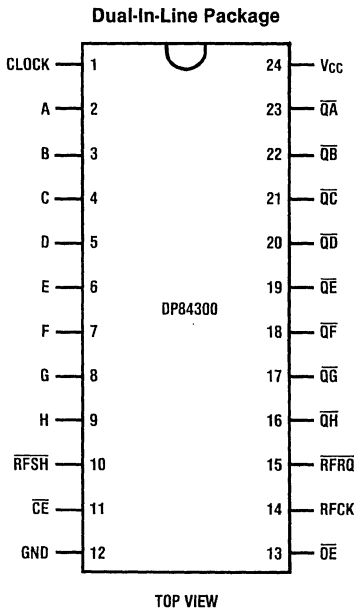
The DP84300 programmable refresh timer is a logic device which produces the desired refresh clock required by all dynamic memory systems.

Additional circuitry has been included in the device to minimize logic required by memory systems to perform refresh control.

Features

- One chip solution to produce RFCK timing for the DP8408 and DP8409 dynamic RAM controllers
- Programmable refresh clock timer allows for a maximum refresh period with most system clocks
- Timing is completely synchronous with the input clock, preventing race conditions present in some memory controllers
- Includes a refresh request output, simplifying the design of refresh logic in discrete controllers

Connection Diagram



Order Number DP84300N-3
See NS Package N24C

Block Diagram

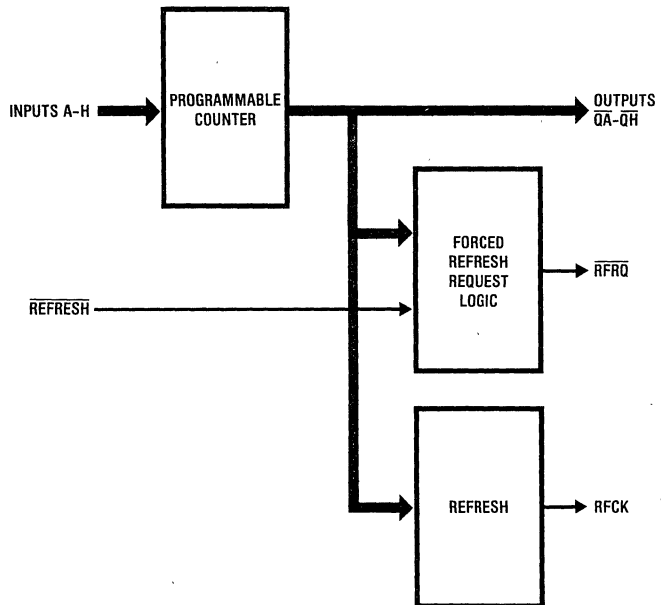


FIGURE 1

Recommended Operating Conditions (Commercial)

	Min	Typ	Max	Units
V _{CC} , Supply Voltage	4.75	5.00	5.25	V
I _{OH} , High Level Output Current			-3.2	mA
I _{OL} , Low Level Output Current			16	mA
T _A , Operating Free Air Temperature	0		75	°C

Electrical Characteristics over recommended operating temperature range

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V _{IH}	High Level Input Voltage		2			V
V _{IL}	Low Level Input Voltage				0.8	V
V _{IC}	Input Clamp Voltage	V _{CC} = Min, I _I = -18 mA			-1.5	V
V _{OH}	High Level Output Voltage	V _{CC} = Min, V _{IH} = 2V, V _{IL} = 0.8V, I _{OH} = Max	2.4			V
V _{OL}	Low Level Output Voltage	V _{CC} = Min, V _{IH} = 2V, V _{IL} = 0.8V, I _{OL} = Max			0.5	V
I _{OZH}	Off-State Output Current High Level Voltage Applied	V _{CC} = Max, V _{IH} = 2V, V _O = 2.4V, V _{IL} = 0.8V			100	μA
I _{OZL}	Off-State Output Current Low Level Voltage Applied	V _{CC} = Max, V _{IH} = 2V, V _O = 0.4V, V _{IL} = 0.8V			-100	μA
I _I	Input Current at Maximum Input Voltage	V _{CC} = Max, V _I = 5.5V			1.0	mA
I _{IH}	High Level Input Current	V _{CC} = Max, V _I = 2.4V			25	μA
I _{IL}	Low Level Input Current	V _{CC} = Max, V _I = 0.4V			-250	μA
I _{OS}	Short Circuit Output Current	V _{CC} = Max	-30		-130	mA
I _{CC}	Supply Current	V _{CC} = Max		150	180	mA

DP84300-3 Switching Characteristics over recommended ranges of temperature and V_{CC}

Symbol	Parameter	Conditions R _L = 667Ω	Commercial T _A = 0°C to +75°C V _{CC} = 5.0V ± 5%			Units
			Min	Typ	Max	
t _{PD}	Clock to Output	C _L = 45 pF		15	25	ns
t _{PZX}	Pin 13 to Output Enable			15	25	ns
t _{PXZ}	Pin 13 to Output Disable	C _L = 5 pF		15	25	ns
t _{PZX}	Input to Output Enable	C _L = 45 pF		25	35	ns
t _{PXZ}	Input to Output Disable	C _L = 5 pF		25	35	ns
t _w	Width of Clock	High	25			ns
		Low	25			ns
t _{SU}	Set-Up Time		35			ns
t _H	Hold Time		0	-15		ns

Mnemonic Description

INPUT SIGNALS

- CLOCK** Provides a time base for the programmable divider.
- A-H** Program inputs A through H. These inputs select the number of clock cycles that will produce one refresh period. These inputs are binary encoded, with input A the LSB, and H the MSB. Additionally, all zeros produce the maximum count of 256, and an input of one will reset the counter to one.
- REFRESH** This input is used to reset the refresh request output (RFRQ).
- OE** Output enable. Places the outputs in TRI-STATE®.
- CE** Counter enable. This input, when low, enables the timer clock and, when high, stalls the timer.

OUTPUT SIGNALS

- QA-QH** Refresh timer outputs QA through QH. Timer starts at programmed input and counts down to one.
- RFRQ** Refresh request. This output goes low on the rising edge of the refresh clock (RFCK). The first input clock edge after the REFRESH input is set low clears this output.
- RFCK** Refresh clock. The period of the clock is determined by setting conditions on input pins A through H. This output is low for 20 clocks, and high for the remainder of the period.

Functional Description

The DP84300 block diagram is shown in Figure 1. This circuit is basically an 8-bit programmable counter. The user selects the number of input clock cycles required per refresh period and sets the binary equivalent on inputs A through H. A signal of that period is produced at the refresh clock (RFCK) output. This output stays low for 20 clock cycles, and goes high for the balance of the period.

When used with the DP8409 dynamic RAM controller, this duty cycle allows the DP8409 the maximum probability to perform a hidden refresh, while still allowing ample time for the DP8409 to perform a forced refresh when needed.

An additional output is provided to ease the design of systems that don't use the DP8409. This output is called refresh request (RFRQ). Refresh request becomes true at the rising edge of refresh clock, and becomes false on the first rising edge of the input clock after a refresh.

In systems where a divisor of more than 256 is needed, an expansion input (CE) has been provided. When this input is high, all counter-related timing is suspended. This excludes actions due to the REFRESH input. The circuits in Figures 2a and 2b show how to expand the range of the timer by 2x or by up to 4096 clock cycles. Figures 3a and 3b show two typical applications using the DP84300.

By using the clock enable input, it is also possible to change the duty cycle of the refresh clock. The circuits in Figures 4a and 4b show how this may be done.

To reset the counter to a known state, select an input divisor of one. On the next clock edge the counter will reset to one. On the next clock edge whatever input divisor that is present on input A-H will be loaded into the counters.

TABLE I. DIVIDER CONSTANTS FOR GENERATION OF A 15.5 μS CLOCK

CPU Clock Frequency	Divisor Input	Actual Period of Output	% Chance of Hidden Refresh
2 MHz	31	15.5 μS	35%
3 MHz	46	15.3 μS	56%
4 MHz	62	15.5 μS	67%
5 MHz	77	15.6 μS	74%
6 MHz	93	15.5 μS	78%
7 MHz	109	15.6 μS	81%
8 MHz	124	15.5 μS	83%
9 MHz	140	15.6 μS	85%
10 MHz	155	15.5 μS	87%

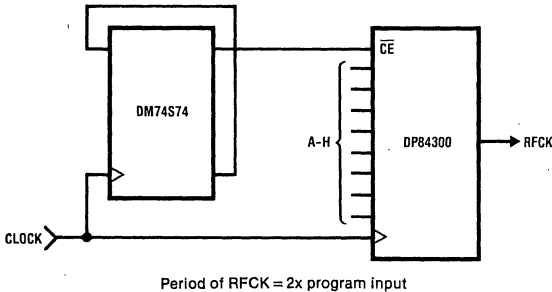


FIGURE 2a. Expansion of Clock Divisor by 2x

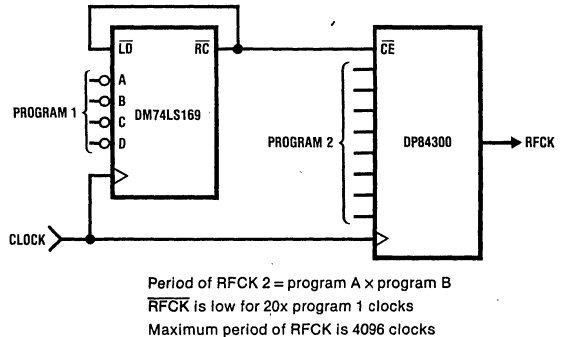


FIGURE 2b. Typical Expansion for the DP84300

Functional Description (Continued)

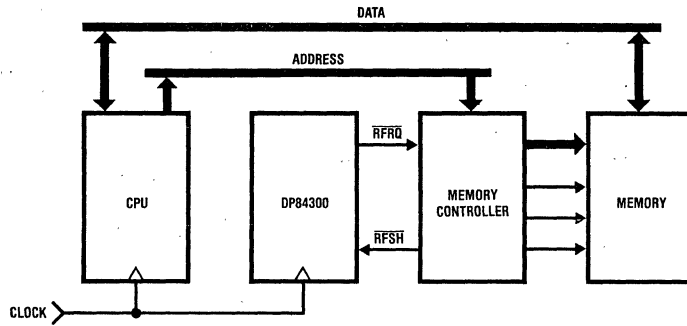


FIGURE 3a. Dynamic Memory System Using DP84300

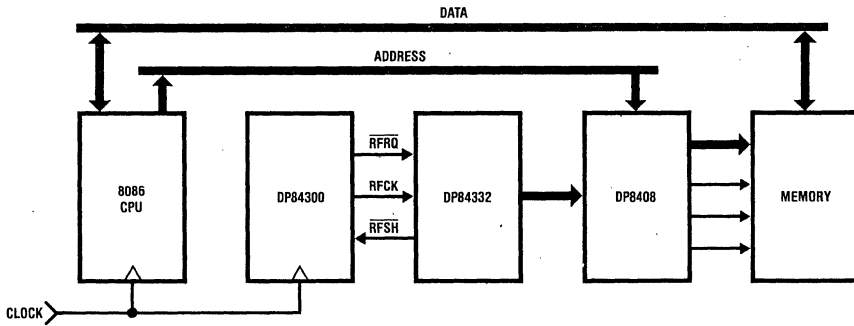


FIGURE 3b. 8086 System Using Dynamic RAMs DP8408, DP84300, and DP84332

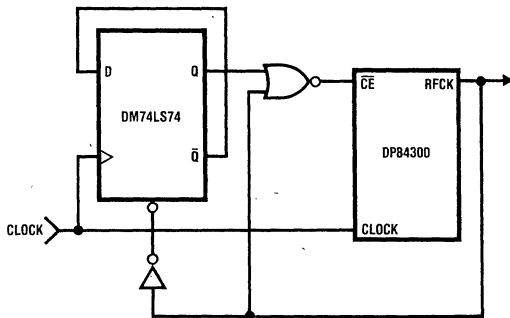


FIGURE 4a. Circuit for Extending RFSCK Low to 40 Clocks

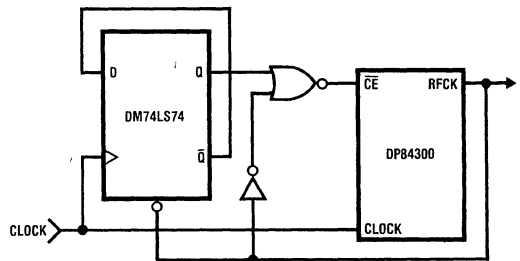
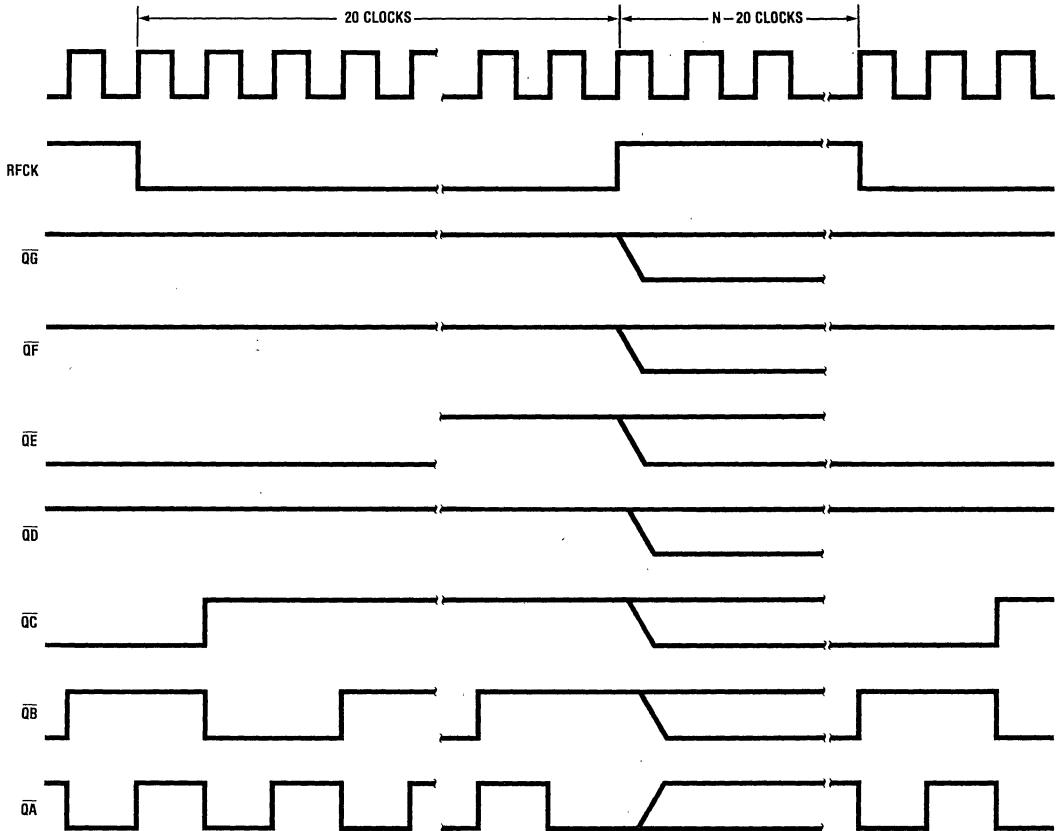


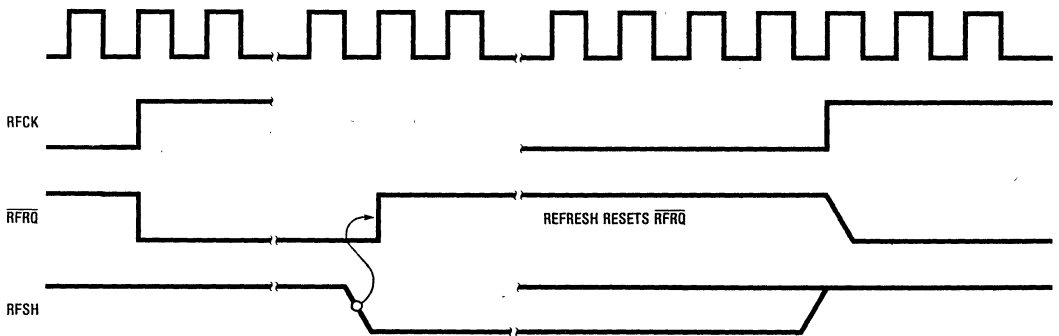
FIGURE 4b. Circuit for Extending RFSCK High by 2x

Timing Diagrams

Refresh Timer Outputs



REFRESH REQUEST ($\overline{\text{RFRQ}}$) Output Timing



DP84312 Dynamic RAM Controller Interface Circuit for the NS16032 CPU

General Description

The DP84312 dynamic RAM controller interface is a Programmable Array Logic (PAL)* device which allows for easy interface between the DP8409 dynamic RAM Controller and the NS16032 microprocessor.

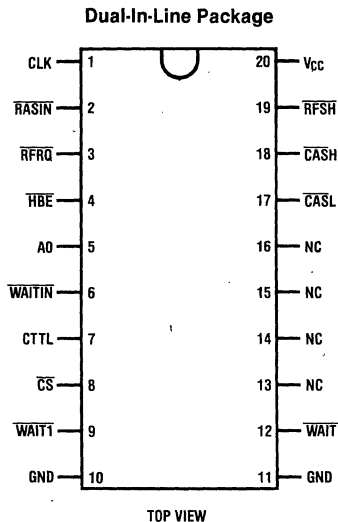
Using timing signals from the NS16201 timing and control unit and the NS16032, the DP84312 supplies all control signals needed to perform memory read, write, byte write, and refresh.

Features

- Low parts count memory system
- Allows the DP8409 to perform hidden refresh
- Allows for the insertion of wait states for slow dynamic RAMs
- Supplies independent $\overline{\text{CAS}}$ s for byte writing
- Possibility of operation at 8MHz with no wait states
- 20-pin 0.3 inch wide package
- Standard National Semiconductor PAL part (DMPAL16R6)
- PAL logic equations can be modified by the user for his specific application and programmed into any of the PALs in the National Semiconductor PAL family, including the new high speed PALs.

*PAL is a registered trademark of Monolithic Memories, Inc.

Connection Diagram



Order Number DP84312N-3
See NS Package N20A

Recommended Operating Conditions (Commercial)

	Min	Typ	Max	Units
V_{CC} , Supply Voltage	4.75	5.00	5.25	V
I_{OH} , High Level Output Current			-3.2	mA
I_{OL} , Low Level Output Current			24	mA
			(Note 2)	
T_A , Operating Free Air Temperature	0		75	°C

Electrical Characteristics over recommended operating temperature range

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	High Level Input Voltage		2			V
V_{IL}	Low Level Input Voltage				0.8	V
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}, I_I = -18 \text{ mA}$			-1.5	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}, V_{IH} = 2\text{V}, V_{IL} = 0.8\text{V}, I_{OH} = \text{Max}$	2.4			V
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}, V_{IH} = 2\text{V}, V_{IL} = 0.8\text{V}, I_{OL} = \text{Max}$			0.5	V
I_{OZH}	Off-State Output Current High Level Voltage Applied	$V_{CC} = \text{Max}, V_{IH} = 2\text{V}, V_O = 2.4\text{V}, V_{IL} = 0.8\text{V}$			100	μA
I_{OZL}	Off-State Output Current Low Level Voltage Applied	$V_{CC} = \text{Max}, V_{IH} = 2\text{V}, V_O = 0.4\text{V}, V_{IL} = 0.8\text{V}$			-100	μA
I_I	Input Current at Maximum Input Voltage	$V_{CC} = \text{Max}, V_I = 5.5\text{V}$			1.0	mA
I_{IH}	High Level Input Current	$V_{CC} = \text{Max}, V_I = 2.4\text{V}$			25	μA
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max}, V_I = 0.4\text{V}$			-250	μA
I_{OS}	Short Circuit Output Current	$V_{CC} = \text{Max}$	-30		-130	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max}$		150	225 (Note 1)	mA

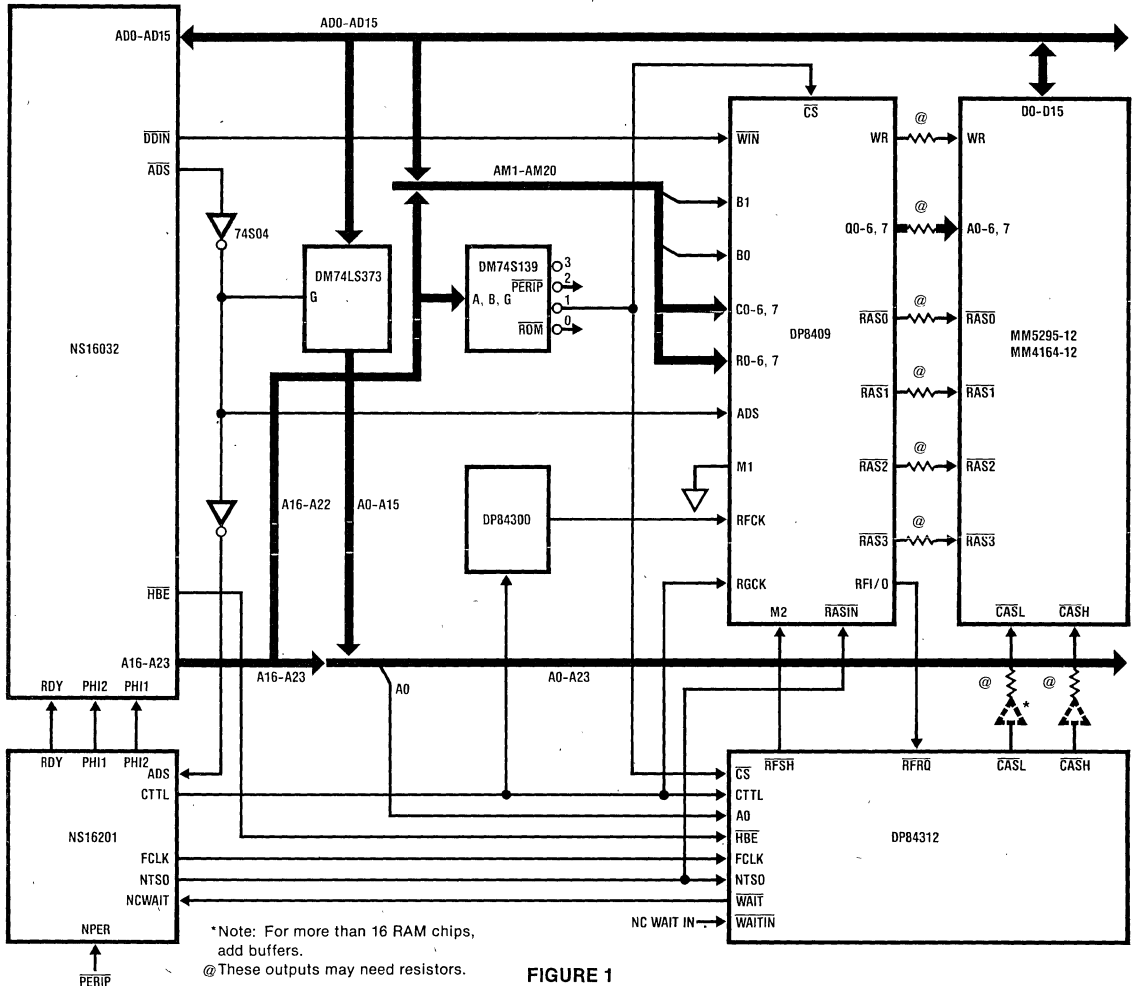
DP84312-3 Switching Characteristics over recommended ranges of temperature and V_{CC}

Symbol	Parameter	Conditions $R_L = 667\Omega$	Commercial $T_A = 0^\circ\text{C to } +75^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 5\%$			Units
			Min	Typ	Max	
t_{WD}	WAITIN to WAIT Delay	$C_L = 45 \text{ pF}$		25	40	ns
t_{PD}	Clock to Output	$C_L = 45 \text{ pF}$		15	25	ns
t_{PZX}	Pin 11 to Output Enable	$C_L = 45 \text{ pF}$		15	25	ns
t_{PXZ}	Pin 11 to Output Disable	$C_L = 5 \text{ pF}$		15	25	ns
t_w	Width of Clock	High	25			ns
		Low	25			ns
t_{su}	Set-Up Time		40			ns
t_h	Hold Time		0	-15		ns

Note 1: $I_{CC} = \text{max}$ at minimum temperature.

Note 2: One output at a time; otherwise 16 mA.

System Block Diagram



*Note: For more than 16 RAM chips, add buffers.
 @ These outputs may need resistors.

FIGURE 1

Mnemonic Description

INPUT SIGNALS

- CLK** Clock input. This clock comes from the FCLK output of the NS16201 timing and control unit, and supplies timing for the internal logic.
- RASIN** $\overline{\text{RAS}}$ input. This input is connected to the NTSO pin of the NS16201. This signal marks the start of a memory cycle.
- RFRQ** Refresh request. The DP8409 requests a forced refresh with this input.
- HBE, A0** Address select inputs. These inputs select the type of write during a write cycle, and select their respective $\overline{\text{CAS}}$ outputs. These inputs must remain stable throughout the memory cycle.
- WAITIN** This wait input allows other devices to use the NCAWAIT line of the NS16201 clock chip.
- CTTL** System clock input. This clock is used to synchronize the memory system to the microprocessor clock.

- CS** Chip select. This input is used to determine if a memory cycle or a hidden refresh cycle is to be performed.
- WAIT1** Insert one wait state. This input allows the use of slow memories with a microprocessor using a fast clock by inserting a wait state in selected memory cycles.
- V_{CC}, GND** 5.0V ± 5%.
- OUTPUT SIGNALS**
- RFSH** Refresh. This output switches the DP8409 to a refresh mode.
- CASH, CASL** $\overline{\text{CAS}}$ outputs. $\overline{\text{CASH}}$ is for controlling the high bank of dynamic RAMs, while $\overline{\text{CASL}}$ controls the $\overline{\text{CAS}}$ line of the lower bank of RAMs. If only eight RAMs are used in each bank, the $\overline{\text{CAS}}$ outputs will directly drive the memories. For larger arrays, these outputs should be buffered with a high current driver, such as the DP84244 MOS driver.
- WAIT** This output controls the insertion of wait states. This output is ORed with $\overline{\text{WAITIN}}$ to allow other devices to insert wait states.

Functional Description

The DP84312 detects the start of a memory cycle when NTSO from the NS16032 timing and control unit (TCU) goes low. The NTSO signal is also used to supply RASIN to the DP8409 dynamic RAM controller. After the DP8409 has latched the row address and supplied the column address to the DRAMs, the DP84312 latches the column address. The DP84312 supplies two CAS outputs, one for the high byte of memory, and the other for the low byte. The ability to control the upper and lower bytes of memory separately is important during a memory write cycle where one byte of memory is to be written (byte write).

By connecting WAIT1 of the DP84312 to ground, all selected memory cycles will have one wait state inserted. This allows an NS16032 operating at high CPU clock frequencies to use slower dynamic RAMs.

Memory refresh may be achieved in one of two ways: hidden or forced. Hidden refresh is accomplished whenever a refresh is requested (internal to the DP8409) and an unselected memory cycle occurs. With a hidden refresh, the DP84312 does nothing while the DP8409 performs the refresh. If no refresh has occurred before the trailing edge of refresh clock, the DP8409 will request a forced refresh. The DP84312 detects this request, and allows the current memory cycle to finish. It then outputs wait states to the CPU, which will hold the CPU if it requests a memory cycle. During this time the DP84312 has switched the dynamic RAM controller to the auto refresh mode, allowing it to perform a refresh. At the end of the refresh cycle,

the DP8409 is switched back to the auto access mode, and the wait is removed after a sufficient RAS precharge time. The total forced refresh takes four CPU clock cycles; of which some, none or all may be actual wait states. If the CPU does not request a memory cycle during this refresh cycle, the refresh will not impact the CPU's performance.

The DP84312 can possibly be operated at 8 MHz with no wait states (WAIT1 = "1") given the following conditions:

- T2 + T3 = 250 ns
- NTSO generation = 15 ns max.
- RASIN to CAS delay DP8409-2 = 130 ns max.
- External CASH,L generation using 74S02 and 74S240
- 7.5 ns (74S02) + 10 ns (74S240) - 7.5 ns (less load on 8409 CAS line) = 10 ns max.
- Transceiver delay = 12 ns max.
- NS16032 data setup = 20 ns max.

$$\therefore \text{Minimum } t_{CAC} = 63 \text{ ns}$$

$$= 250 - 15 - 130 - 10 - 12 - 20$$

- Minimum $t_{RAS} = 250 \text{ ns}$
- Minimum $t_{RP} = 250 \text{ ns}$
- Minimum $t_{RAH} = 20 \text{ ns}$

The DP84312 is a standard National Semiconductor PAL part (DMPAL16R6). The user can modify the PAL equations to support his particular application. The DP84312 logic equations, function table (functional test), and logic diagram can be seen at the end of this Data Sheet.

Timing Diagrams

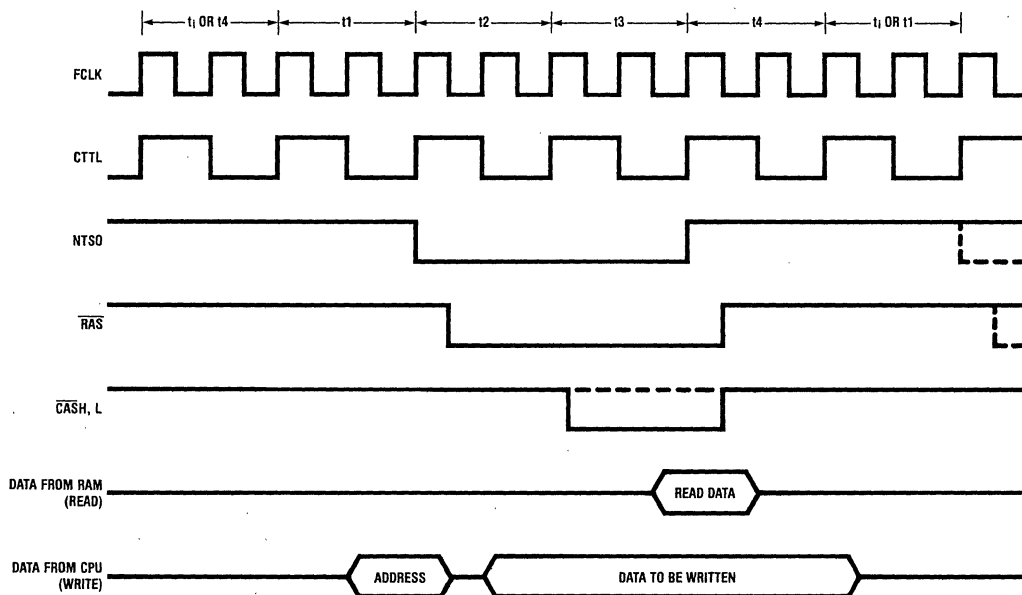


FIGURE 2a. Read, Write, or Hidden Refresh Memory Cycle for the NS16032-DP8409 Interface

Timing Diagrams (Continued)

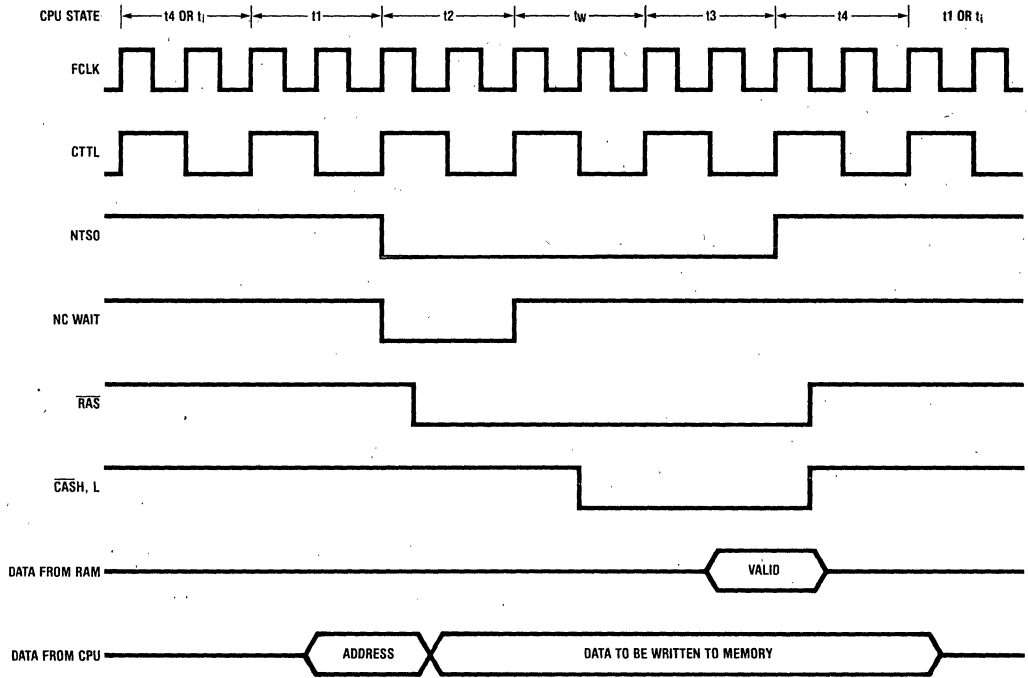


FIGURE 2b. Read or Write Memory Cycle with One Wait

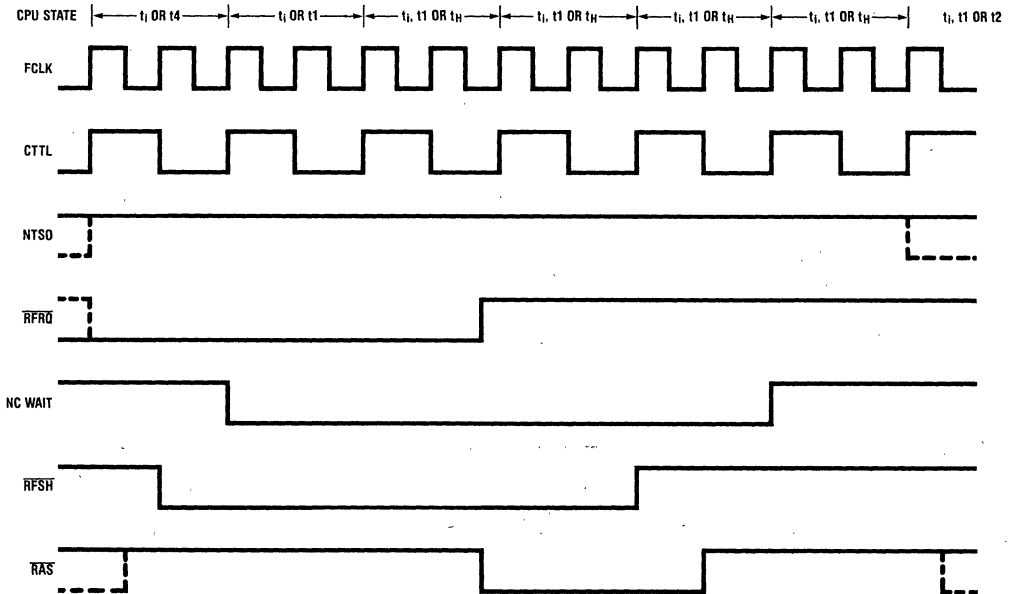


FIGURE 2c. Forced Refresh Cycle

PAL16R6
 DP84312
 Interface Circuit for the NS16032/DP8409
 Memory System
 CK NTSO /RFRQ /HBE A0 /WAITIN CTTL /CS /SLOW
 GND /OE /WAIT /D /C /B /A /CASL /CASH /RFSH VCC

CASH: = A • /B • /C • D • HBE • CS +
 /A • /B • D • HBE • CS

CASL: = A • /B • /C • D • /A0 • CS +
 /A • /B • D /A0 • CS

A := /A • /B • /C • /D • /NTSO • CS • SLOW +
 B • /C • /D +
 A • /C • /D +
 A • B

B := /A • /B • /C • /D • NTSO • RFRQ • CTTL +
 /A • B +
 A • B • /C +
 B • C • D

C := /A • /B • /C • /D • NTSO • RFRQ • CTTL +
 /A • /B • D +
 A • B • D +
 B • C • /D +
 /A • /B • C • /D • /NTSO

D := /A • /B • /C • /D • /NTSO • CS • /SLOW +
 /A • /B • /C • /D • /NTSO • /CS +
 A • /C +
 /B • /C • D +
 /A • B • C

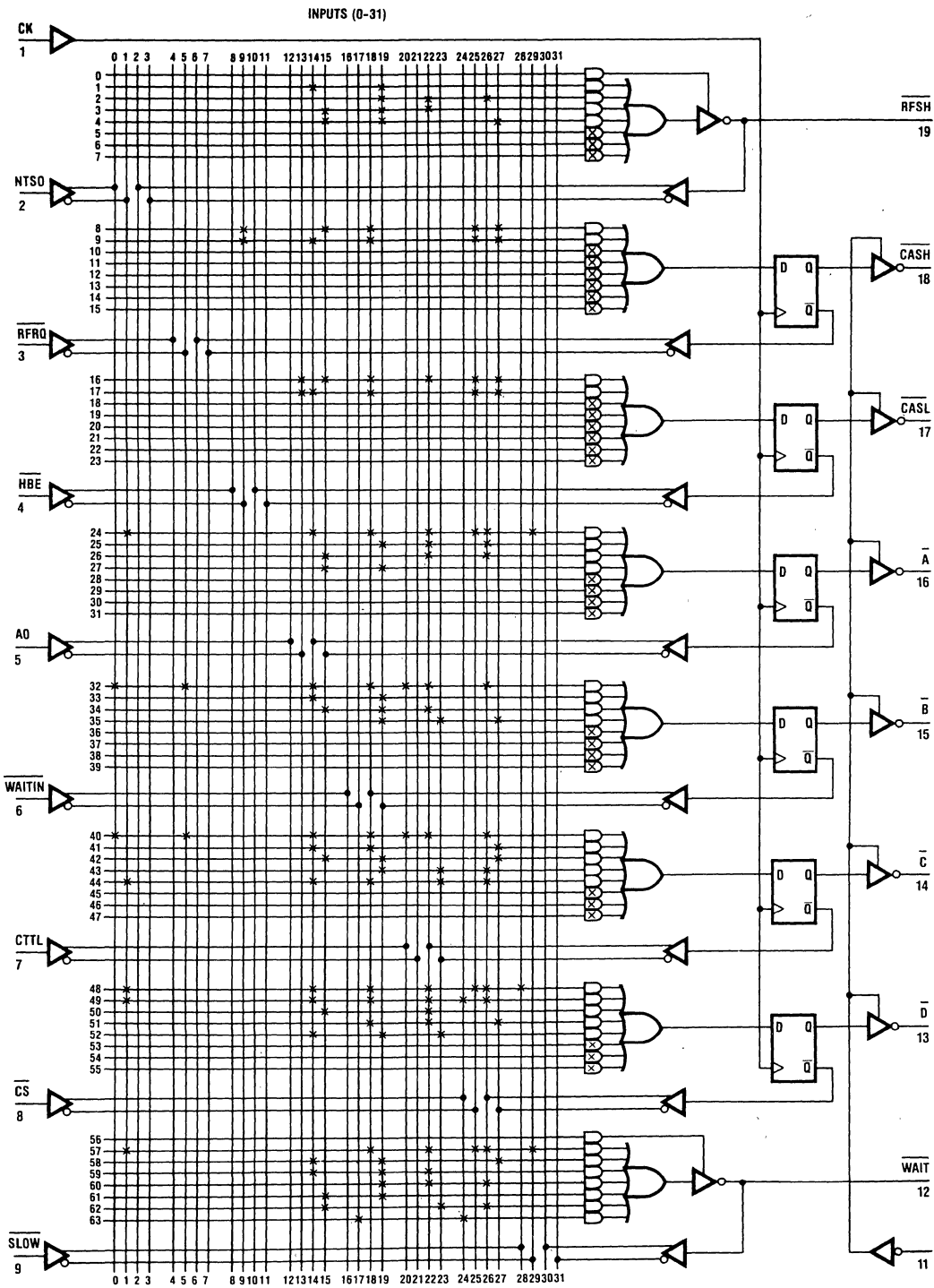
IF (VCC) WAIT = /B • /C • /D • /NTSO • CS • SLOW +
 /A • B • D +
 B • /C • /D +
 A • B +
 A • C • /D +
 /CS • WAITIN

IF (VCC) RFSH = /A • B +
 B • /C • /D +
 A • B • /C +
 A • B • C

Function Table

CK	NTSO	RFRQ	HBE	A0	WAITIN	CTTL	CS	SLOW	OE	CASH	CASL	A	B	C	D	WAIT	RFSH
C	H	H	L	L	H	H	H	H	L	X	X	X	X	X	X	X	X
C	H	H	L	L	H	H	H	H	L	L	L	L	L	L	L	L	L
C	L	X	L	L	H	X	L	H	L	L	L	L	L	L	H	L	L
C	L	X	L	L	H	X	L	H	L	H	H	L	L	H	L	L	L
C	X	X	L	L	H	X	L	H	L	L	L	L	L	L	L	L	L
C	H	X	L	L	H	X	L	L	L	L	L	H	L	L	L	H	L
C	X	X	L	H	H	X	L	L	L	L	L	H	L	L	H	L	L
C	X	X	L	H	H	X	L	L	L	H	L	L	L	H	H	L	L
C	X	X	L	H	H	X	L	L	L	H	L	L	L	H	L	L	L
C	H	X	L	L	H	X	H	H	L	L	L	L	L	L	H	L	L
C	X	X	L	L	L	X	H	X	L	L	L	L	L	H	H	H	L
C	H	X	L	L	H	X	H	X	L	L	L	L	L	H	L	L	L
C	H	X	L	L	H	X	H	X	L	L	L	L	L	H	L	L	L
C	H	L	X	X	H	H	X	X	L	L	L	L	H	H	L	L	H
C	H	X	X	X	H	H	X	X	L	L	L	L	H	H	H	H	H
C	H	H	X	X	H	L	X	X	L	L	L	L	H	L	L	H	H
C	H	H	X	X	H	H	X	X	L	L	L	L	H	L	L	H	H
C	H	H	X	X	H	H	X	X	L	L	L	L	H	H	L	H	H
C	H	H	X	X	H	L	X	X	L	L	L	L	H	H	L	H	H
C	H	H	X	X	H	H	X	X	L	L	L	L	H	H	L	H	H
C	L	H	X	X	L	X	H	X	L	L	L	L	L	H	H	H	L
C	L	H	X	X	L	X	H	X	L	L	L	L	L	H	L	H	L
C	L	X	X	X	H	X	H	X	L	L	L	L	L	H	L	L	L
C	H	X	X	X	H	X	H	X	L	L	L	L	L	L	L	L	L
C	H	H	H	H	H	H	H	H	H	Z	Z	Z	Z	Z	Z	Z	Z

PRODUCT TERMS (0-31)



7

DP84322 Dynamic RAM Controller Interface Circuit for the 68000 CPU

General Description

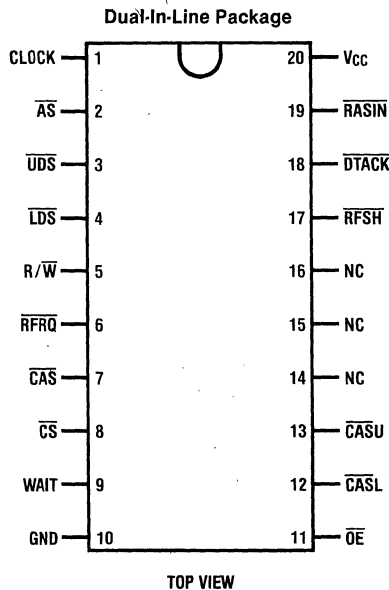
The DP84322 dynamic RAM controller interface is a Programmable Array Logic (PAL)* device which allows for easy interface between the DP8409 dynamic RAM Controller and the 68000 microprocessor.

The DP84322 supplies all the control signals needed to perform memory read, write and refresh. Logic is included for inserting a wait state when using fast CPUs.

Features

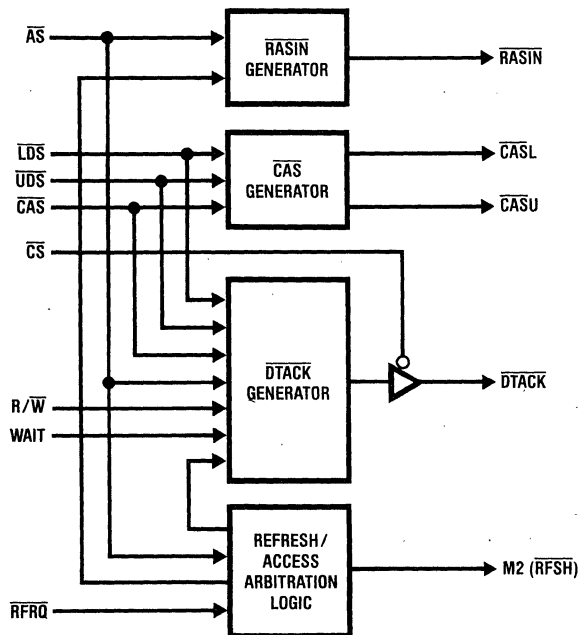
- Provides 3-chip solution for the 68000 CPU and dynamic RAM interface
- Works with all 68000 speed versions
- Possibility of operation at 8 MHz with no wait states
- Performs hidden refresh
- \overline{DTACK} is automatically inserted for both memory access and memory refresh
- Performs forced refresh using typically 4 CPU clocks
- Standard National Semiconductor PAL part (DMPAL16R4)
- PAL logic equations can be modified by the user for his specific application and programmed into any of the PAL in the National Semiconductor PAL family, including the new high speed PAL's.

Connection Diagram



Order Number DP84322N-3
See NS package N20A

Block Diagram



*PAL is a registered trademark of Monolithic Memories, Inc.

Recommended Operating Conditions (Commercial)

	Min	Typ	Max	Units
V_{CC} , Supply Voltage	4.75	5.00	5.25	V
I_{OH} , High Level Output Current			-3.2	mA
I_{OL} , Low Level Output Current			24	mA
			(Note 2)	
T_A , Operating Free Air Temperature	0		75	°C

Electrical Characteristics over recommended operating temperature range

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	High Level Input Voltage		2			V
V_{IL}	Low Level Input Voltage				0.8	V
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}$, $I_I = -18 \text{ mA}$			-1.5	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}$, $V_{IH} = 2\text{V}$, $V_{IL} = 0.8\text{V}$, $I_{OH} = \text{Max}$	2.4			V
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}$, $V_{IH} = 2\text{V}$, $V_{IL} = 0.8\text{V}$, $I_{OL} = \text{Max}$			0.5	V
I_{OZH}	Off-State Output Current High Level Voltage Applied	$V_{CC} = \text{Max}$, $V_{IH} = 2\text{V}$, $V_O = 2.4\text{V}$, $V_{IL} = 0.8\text{V}$			100	μA
I_{OZL}	Off-State Output Current Low Level Voltage Applied	$V_{CC} = \text{Max}$, $V_{IH} = 2\text{V}$, $V_O = 0.4\text{V}$, $V_{IL} = 0.8\text{V}$			-100	μA
I_I	Input Current at Maximum Input Voltage	$V_{CC} = \text{Max}$, $V_I = 5.5\text{V}$			1.0	mA
I_{IH}	High Level Input Current	$V_{CC} = \text{Max}$, $V_I = 2.4\text{V}$			25	μA
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max}$, $V_I = 0.4\text{V}$			-250	μA
I_{OS}	Short Circuit Output Current	$V_{CC} = \text{Max}$	-30		-130	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max}$		150	225 (Note 1)	mA

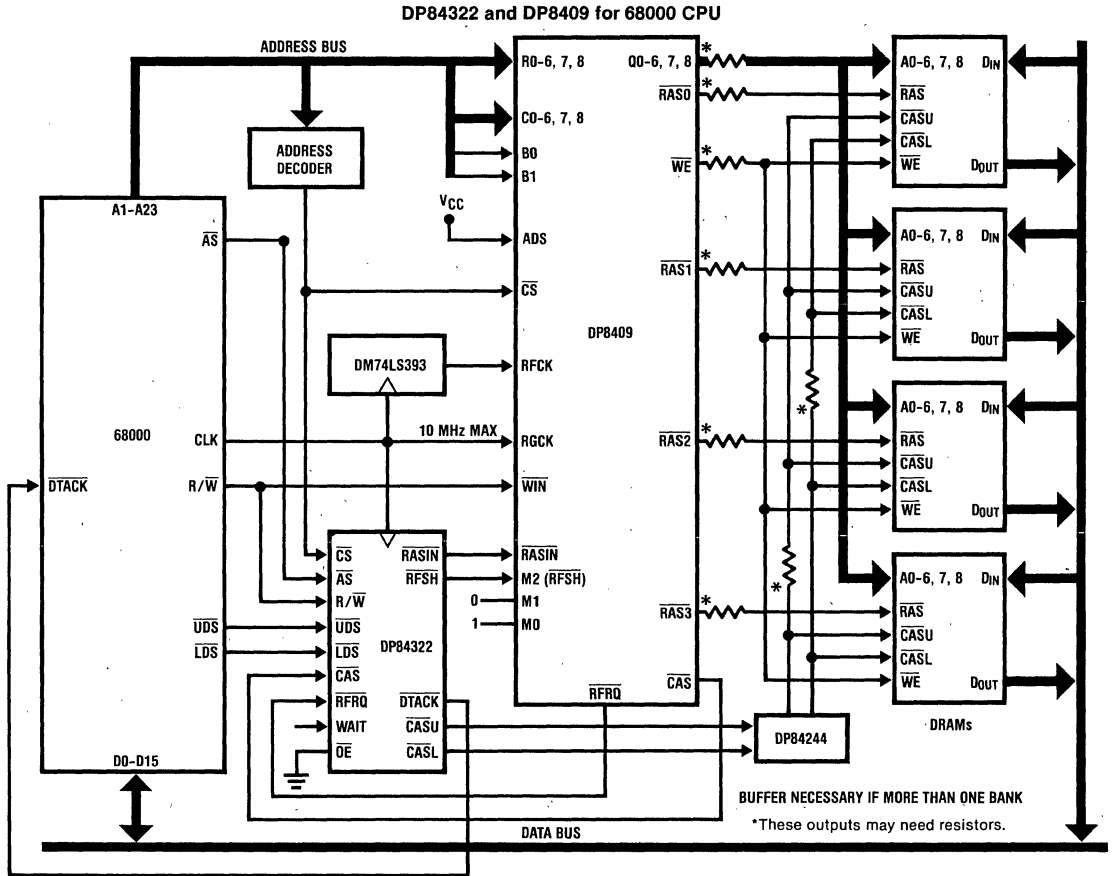
Switching Characteristics over recommended ranges of temperature and V_{CC}

Symbol	Parameter		Test Conditions $R_L = 667\Omega$	Commercial $T_A = 0^\circ\text{C to } +75^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 5\%$			Units
				Min	Typ	Max	
t_{PD}	Input to Output		$C_L = 45 \text{ pF}$		25	40	ns
t_{PD}	Clock to Output				15	25	ns
t_{PZX}	Pin 11 to Output Enable				15	25	ns
t_{PXZ}	Pin 11 to Output Disable		$C_L = 5 \text{ pF}$		15	25	ns
t_{PZX}	Input to Output Enable		$C_L = 45 \text{ pF}$		25	40	ns
t_{PXZ}	Input to Output Disable		$C_L = 5 \text{ pF}$		25	40	ns
t_w	Width of Clock	High		25			ns
		Low		25			ns
t_{su}	Set-Up Time			40			ns
t_h	Hold Time			0	-15		ns

Note 1: $I_{CC} = \text{max}$ at minimum temperature.

Note 2: One output at a time; otherwise 16 mA.

System Block Diagram



BUFFER NECESSARY IF MORE THAN ONE BANK
*These outputs may need resistors.

Mnemonic Description

INPUT SIGNALS

- CLOCK** The clock signal determines the timing of the outputs and should be connected directly to the 68000 clock input.
- AS** Address Strobe from the 68000 CPU. This input is used to generate RASIN to the DP8409.
- UDS, LDS** Upper and lower data strobe from the 68000 CPU. These inputs, together with AS, R/W, provide DTACK to the 68000.
- R/W** Read/write from the 68000 CPU, when WAIT=0. Selects processor speed when WAIT=1 ("1" = 4 to 6 MHz, "0" = 8 MHz).
- CAS** Column Address Strobe from the DP8409. This input, together with LDS and UDS, provides two separate CAS outputs for accessing upper and lower memory data bytes.
- CS** Chip Select. This input enables DTACK output. CS=0, DTACK output is enabled; CS=1, DTACK output is TRI-STATE®.
- RFRQ** Refresh Request. This input requests the DP84322 for a forced refresh.
- WAIT** This input allows the necessary wait state to be inserted for memory access cycles.

OUTPUT SIGNALS

- RASIN** This output provides a memory cycle start signal to the DP8409 and provides RAS timing during hidden refresh.
- CASU, CASL** These signals are the separate CAS outputs needed for byte writing.
- DTACK** This output is used to insert wait states into the 68000 memory cycles when selected and during a forced refresh cycle where the CPU attempts to access the memory. This output is enabled when CS input is low and TRI-STATE® when CS is high.
- RFSH** This output controls the mode of the DP8409. It always goes low for 4 CPU clock periods when AS is inactive and a forced refresh is requested through RFRQ input. This allows the DP8409 to perform an automatic forced refresh.

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Functional Description

MEMORY ACCESS

As a 68000 bus cycle begins, a valid address is output on the address bus A1-A23. This address is decoded to provide Chip Select (\overline{CS}) to the DP8409. After the address becomes valid, \overline{AS} goes low and it is used to set \overline{RASIN} low from the DP84322 interface circuit. Note that \overline{CS} must go low for a minimum of 10 ns before the assertion of \overline{RASIN} for a proper memory access. As an example, with a 8 MHz 68000, the address is valid for at least 30 ns before \overline{AS} goes active. \overline{AS} then has to ripple through the DP84322 to produce \overline{RASIN} . This means the address is valid for a minimum of 40 ns before \overline{RASIN} goes low, and the decoding of \overline{CS} should take less than 30 ns. At this speed the DM74LS138 or DM74LS139 decoders can be selected to guarantee the 10 ns minimum required by \overline{CS} set-up time going low before the access \overline{RASIN} goes low (t_{CSRL} of the DP8409). This is important because a false hidden refresh may take place when the minimum t_{CSRL} is not met. Typically \overline{RASIN} occurs at the end of S2. Subsequently, selected \overline{RAS} output, row to column select and then \overline{CAS} will automatically follow \overline{RASIN} as determined by mode 5 of the DP8409. Mode 5 guarantees a 30 ns minimum for row address hold time (t_{RAH}) and a minimum of 8 ns column address set-up time (t_{ASC}). If the system requires instructions that use byte writing, then \overline{CASU} and \overline{CASL} are needed for accessing upper and lower memory data bytes, and they are provided by the DP84322. In the DP84322, \overline{LDS} and \overline{UDS} are gated with \overline{CAS} from the DP8409 to provide \overline{CASL} and \overline{CASU} , therefore designers need not be concerned about delaying \overline{CAS} during write cycles to assure valid data being written into memory. The 8 MHz 68000 specifies during a write cycle that data output is valid for a minimum of 30 ns before \overline{DS} goes active. Thus, \overline{CASL} and \overline{CASU} will not go low for at least 40 ns after the output data becomes stable, guaranteeing the 68000 valid data is written to memory.

Furthermore, the gating of \overline{UDS} , \overline{LDS} and \overline{CAS} allows the DP84322 interface controller to support the test and set instruction (TAS). The 68000 utilizes the read-modify-write cycle to execute this instruction. The TAS instruction provides a method of communication between processors in a multiple processor system. Because of the nature of this instruction, in the 68000, this cycle is indivisible and the Address Strobe \overline{AS} is asserted throughout the entire cycle, however \overline{DS} is asserted twice for two accesses: a read then a write. The dynamic RAM controller and the DP84322 respond to this read-modify-write instruction as follows (refer to the TAS instruction timing diagram for clarification). First, the selected \overline{RAS} goes low as a result of \overline{AS} going low, and this \overline{RAS} output will remain low throughout the entire cycle. Then the DP84322's selected \overline{CAS} output (\overline{CASL} or \overline{CASU}) goes low to read the specified data byte. After this read, \overline{DS} goes high causing the selected \overline{CAS} to go high. A few clocks later R/W goes low and then \overline{DS} is re-asserted. As \overline{DS} goes low, the selected \overline{CAS} goes low strobing the CPU's modified data into memory, after which the cycle is ended when \overline{AS} goes high.

The two \overline{CAS} outputs from the DP84322, however, can only drive one memory bank. For additional driving capability, a memory driver such as the DP84244 should be added to drive loads of up to 500 pF.

Since this DP84322 interface circuit is designed to operate with all of the 68000 speed versions, a status input called WAIT is used to distinguish the 8 MHz from the others. The

WAIT input should be set low for 6 MHz or less allowing full speed of operation with no wait states. Data Transfer Acknowledge input (\overline{DTACK}) of the 68000 at these speeds is automatically inserted during S2 for every memory transaction cycle and is then negated at the end of that cycle when \overline{UDS} and/or \overline{LDS} go high. For the 8 MHz 68000 however, a wait state is required for every memory transaction cycle. At these speeds, the WAIT input is set high, selecting the DP8409's \overline{CAS} output to generate \overline{DTACK} and again \overline{DTACK} is negated at the end of the cycle when \overline{UDS} or \overline{LDS} goes high. Note that \overline{DTACK} output is enabled only when the DP8409's \overline{CS} is low. Therefore when the 68000 is accessing I/O or ROM (in other words, when the DP8409 is not selected), the DP84322's \overline{DTACK} output goes high impedance logic '1' through the external pull-up resistor and it is now up to the designer to supply \overline{DTACK} for a proper bus cycle.

The following table indicates the maximum memory speed in terms of the DRAM timing parameters: t_{CAC} (access-time from \overline{CAS}) and t_{RP} (\overline{RAS} precharge time) required by different 68000 speed versions:

Microprocessor Clock	Maximum t_{CAC}	Minimum t_{RP}	Minimum t_{RAS}
8 MHz	125 ns	140 ns	220 ns
6 MHz	90 ns	170 ns	290 ns
4 MHz	270 ns	280 ns	450 ns

Pin 5 ($\overline{R/W}$ input to the DP84322) is not used as $\overline{R/W}$ when the WAIT input is high. Therefore, when WAIT is high and pin 5 is low, this is configured for the 8 MHz 68000. The dynamic RAM controller in this configuration operates in mode 5 and mode 1.

When both WAIT and pin 5 are high, this is configured for 4 MHz and 6 MHz 68000, allowing only two microprocessor clocks for memory refresh. Furthermore, the designer can use the DP8408 because the dynamic RAM controller now operates in mode 0 and mode 5 or mode 6. In addition, the programmable refresh timer, DP84300, should be used to determine the refresh rate (RFCK) and to provide the refresh request (\overline{RFRQ}) input to the DP84322. The refresh timer can provide over two hundred different divisors. \overline{RFRQ} is given at the beginning of every RFCK cycle and remains active until M2 goes low for memory refresh. The DP84322 samples \overline{RFRQ} when \overline{AS} is high, then sets M2 low for two microprocessor clocks, taking the DP8408 or DP8409 to the external control refresh mode. \overline{RASIN} for this refresh is also issued by the DP84322. If a memory access is pending, \overline{RASIN} for this access will not be given until it is delayed for approximately one microprocessor clock, allowing \overline{RAS} precharge time for the dynamic RAMs.

The following table indicates different memory speeds in terms of the DRAM parameters required by 4 MHz and 6 MHz 68000:

Microprocessor Clock	Maximum t_{CAC}	Minimum t_{RAS}	Minimum t_{RP}	Minimum t_{RAH}
4 MHz	290 ns	200 ns	225 ns	20 ns
6 MHz	110 ns	125 ns	140 ns	20 ns

DP8408, DP8409 operate in mode 6 and mode 0.

Functional Description (Continued)

When $\overline{\text{WAIT}} = 1$, pin 5 = 0 (8 MHz), the PAL controller supports read and write cycles with one inserted wait state, forced refresh with five wait states inserted if $\overline{\text{CS}}$ is valid, and hidden refresh. This PAL mode does not support the TAS instruction.

When $\overline{\text{WAIT}} = \text{pin } 5 = 1$ (4-6 MHz), the PAL controller supports read and write cycles with no wait states inserted, and forced refresh with two wait states inserted if $\overline{\text{CS}}$ is valid. This PAL mode does not support the TAS instruction and only supports hidden refresh when used in mode 5 with the DP8409 controller.

The DP84322 can possibly be operated at 8 MHz with no wait states ($\overline{\text{WAIT}} = "0"$) given the following conditions:

FAST PAL (PAL16R4A)

$S2 + S3 + S4 + S5 = 250 \text{ ns}$

$\overline{\text{RASIN}}$ delay = 60 ns ($\overline{\text{AS}}$ low max.)

+ 25 ns (Fast PAL delay) = 85 ns max.

$\overline{\text{RASIN}}$ to $\overline{\text{CAS}}$ delay DP8409-2 = 130 ns max.

External $\overline{\text{CASH,L}}$ generation using 74S02 and 74S240

7.5 ns (74S02) + 10 ns (74S240) - 7.5 ns (less load on 8409 $\overline{\text{CAS}}$ line) = 10 ns max.

Transceiver delay (74LS245) = 12 ns max.

68000 data setup into $S6 = 40 \text{ ns min.}$

\therefore Minimum $t_{\text{CAC}} = 53 \text{ ns.}$

= 250 - 85 - 130 - 10 - 12 + 40

Minimum $t_{\text{RAS}} = 240 \text{ ns}$

Minimum $t_{\text{RP}} = 150 \text{ ns}$

Minimum $t_{\text{RAH}} = 20 \text{ ns}$

REFRESH CYCLE

Since the access sequence timing is automatically derived from $\overline{\text{RASIN}}$ in mode 5, $\overline{\text{R/C}}$ and $\overline{\text{CASIN}}$ are not used and now become Refresh Clock (RFCK) and $\overline{\text{RAS}}$ -generator clock (RGCK) respectively. The Refresh Clock RFCK may be divided down from RGCK, which is the microprocessor clock, using the DM74LS393 or DM74LS390. RFCK provides the refresh time interval and RGCK the fast clock for all- $\overline{\text{RAS}}$ refresh if forced refreshing is necessary. The DP8409 offers both hidden refresh in mode 5 and forced refresh in mode 1 with priority placed on hidden refreshing. Assume 128 rows are to be refreshed, then a 16 μs maximum clock period is needed for RFCK to distribute refreshing of all the rows over the 2 ms period.

The DP8409 provides hidden refreshing in mode 5 when the refresh clock (RFCK) is high and the microprocessor is not accessing RAM. In other words, when the DP8409's chip select is inactive because the microprocessor is

accessing elsewhere, all four $\overline{\text{RAS}}$ outputs follow $\overline{\text{RASIN}}$, strobing the contents of the on-chip refresh counter to every memory bank. $\overline{\text{RASIN}}$ going high terminates the hidden refresh and also increments the refresh counter, preparing it for the next refresh cycle. Once a hidden refresh has taken place, a forced refresh will not be requested by the DP8409 for the current RFCK cycle.

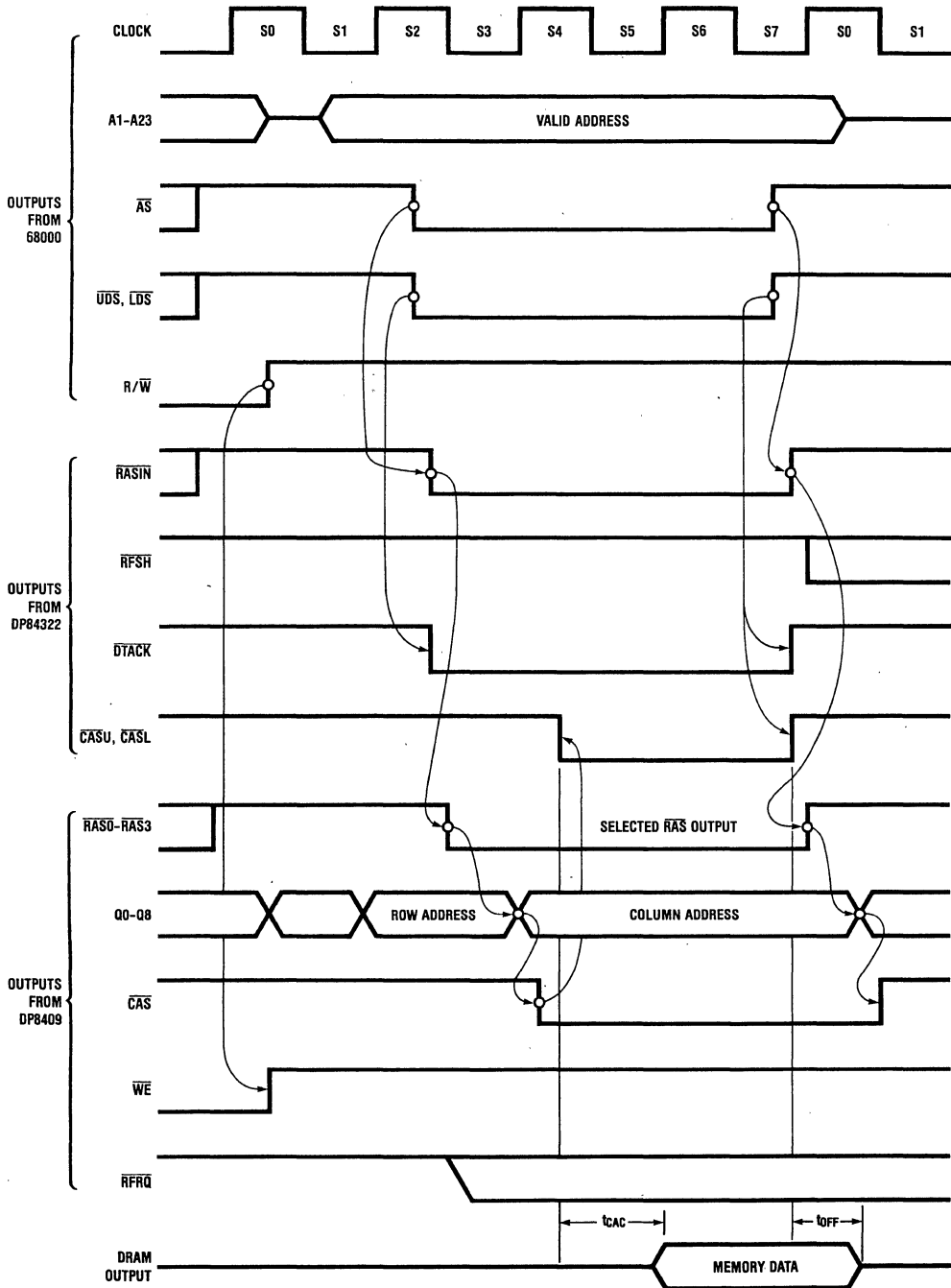
However, if the microprocessor continuously accessed the DP8409 and memory while RFCK was high, a hidden refresh could not have taken place and now the system must force a refresh. Immediately after RFCK goes low, the Refresh Request signal ($\overline{\text{RFRQ}}$) from the DP8409 goes low, indicating a forced refresh is necessary. First, when $\overline{\text{RFRQ}}$ goes low any time during $S2$ to $S7$, the controller interface circuit waits until the end of the current memory access cycle and then sets $M2$ ($\overline{\text{RFSH}}$) low. This refresh takes four microprocessor clocks to complete. If the current cycle is another memory cycle, the 68000 will automatically be put in four wait states. Alternately, when $\overline{\text{RFRQ}}$ goes low while $\overline{\text{AS}}$ is high during $S0$ to $S1$, $M2$ is now set low at $S2$. Therefore, it requires an additional microprocessor clock for this refresh. Once the DP8409 is in mode 1 forced refresh, all the $\overline{\text{RAS}}$ outputs remain high until two RGCK trailing edges after $M2$ goes low, when all $\overline{\text{RAS}}$ outputs go low. This allows a minimum of one and a half clock periods of RGCK for $\overline{\text{RAS}}$ precharge time. As specified in the DP8409 data sheet, the $\overline{\text{RAS}}$ outputs remain low for two clock periods of RGCK. The refresh counter is incremented as the $\overline{\text{RAS}}$ outputs go high. Once the forced refresh has ended, $M2$ is brought high, the DP8409 back to mode 5 auto access. Note that $\overline{\text{RASIN}}$ for the pending access is not given until it has been delayed for a full microprocessor clock, allowing $\overline{\text{RAS}}$ precharge time for the coming access.

If the 68000 bus is inactive (i.e., the 68000's instruction queue is full, or the 68000 is executing internal operations such as a multiply instruction, or the 68000 is in halt state...) and a refresh has been requested, a refresh will also take place because $\overline{\text{RFRQ}}$ is continuously sampled while $\overline{\text{AS}}$ is high. Therefore, refreshing under these conditions will be transparent to the microprocessor. Consequently, the system throughput is increased because the DP84322 allows refreshing while the 68000 bus is inactive.

The 84322 is a standard National Semiconductor PAL part (DMPAL16R4). The user can modify the PAL equations to support his particular application. The 84322 logic equations function table (functional test), and logic diagram can be seen at the end of this data sheet.

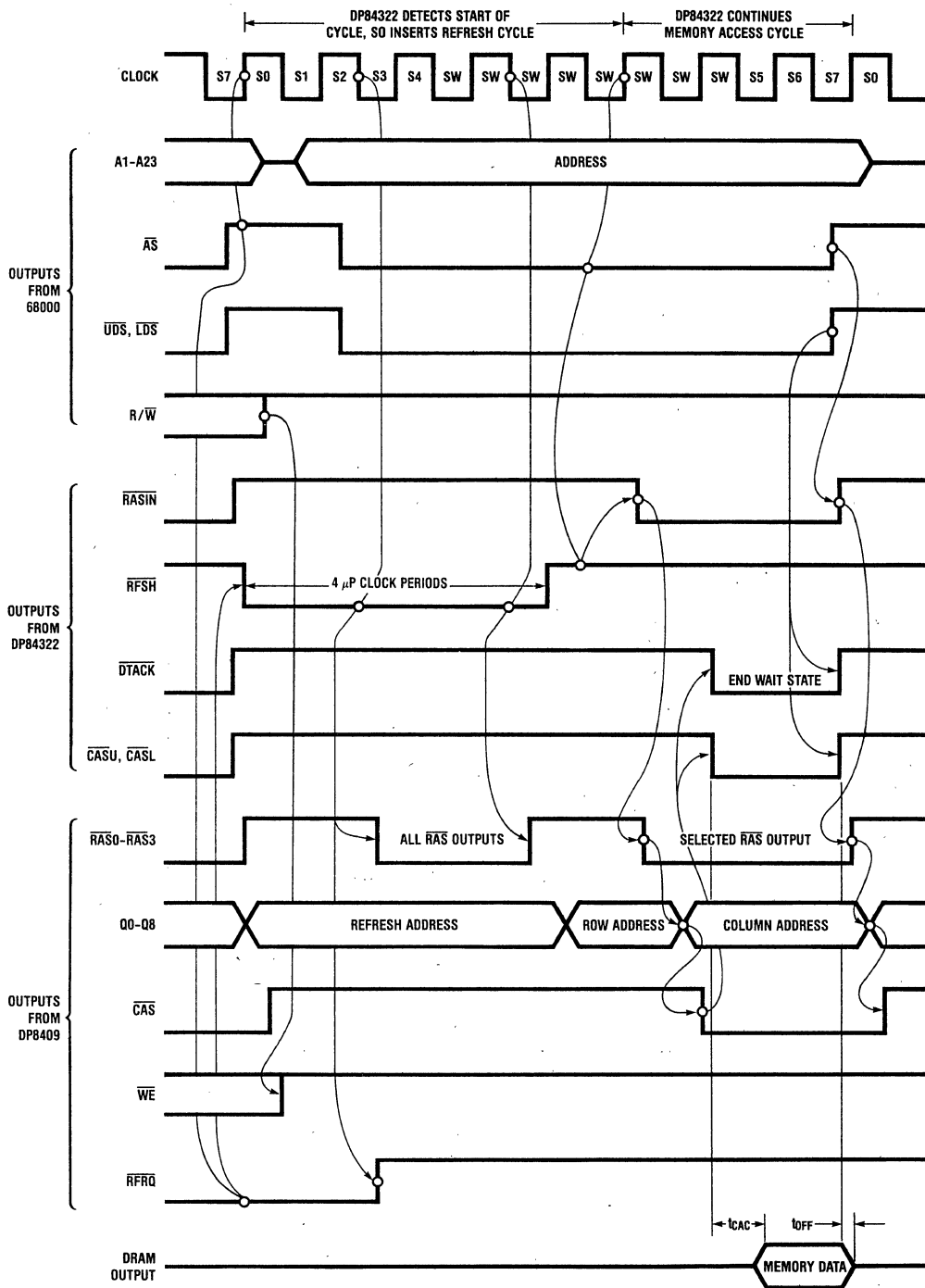
Timing Diagrams

68000 Memory Read Cycle (Wait = 0, Pin 5 = R/W)



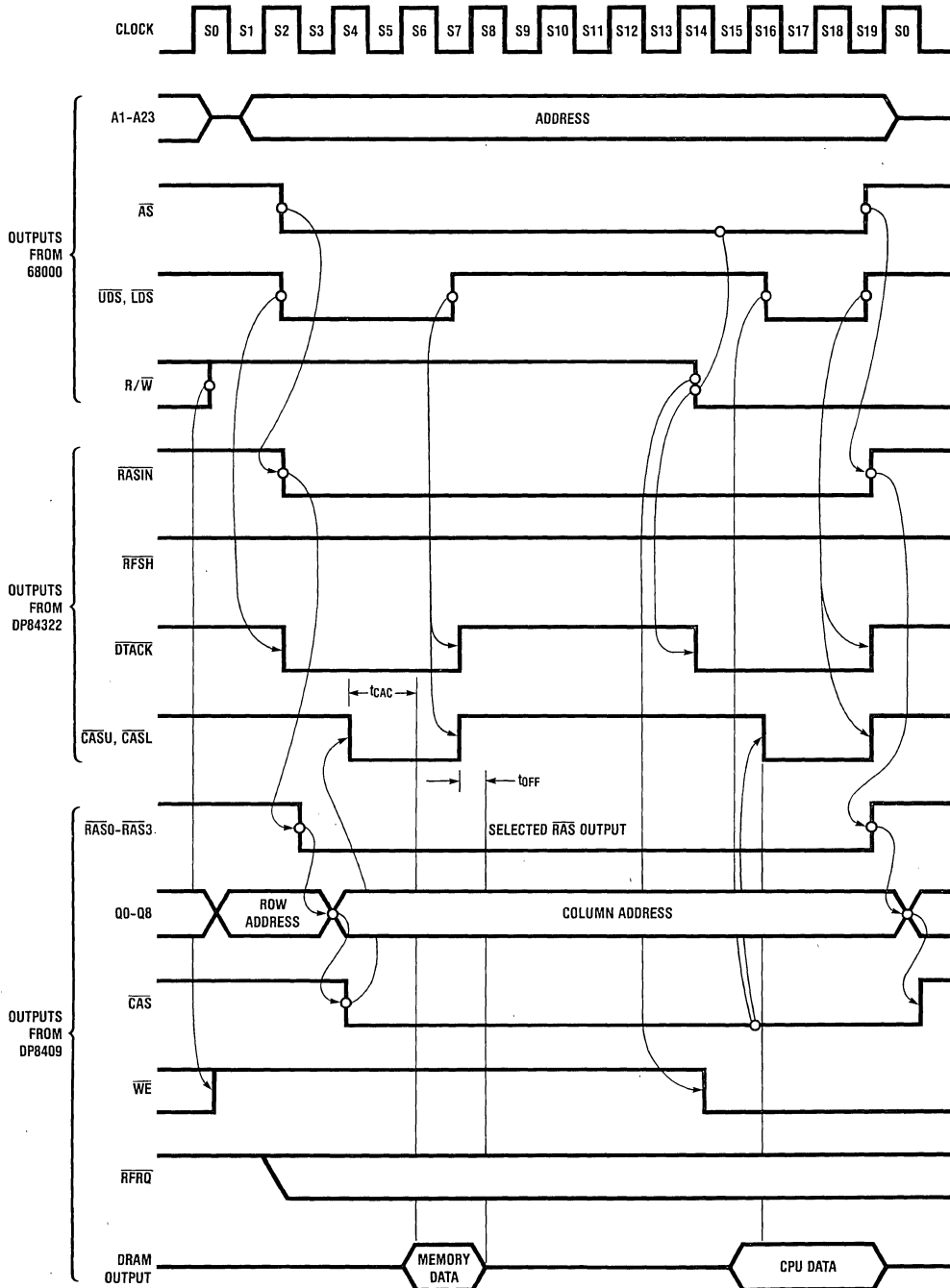
Timing Diagrams (Continued)

68000 Memory Read Cycle and Forced Refresh (Wait = 0, Pin 5 = R/W)
 (4 wait clock periods inserted for forced refresh)



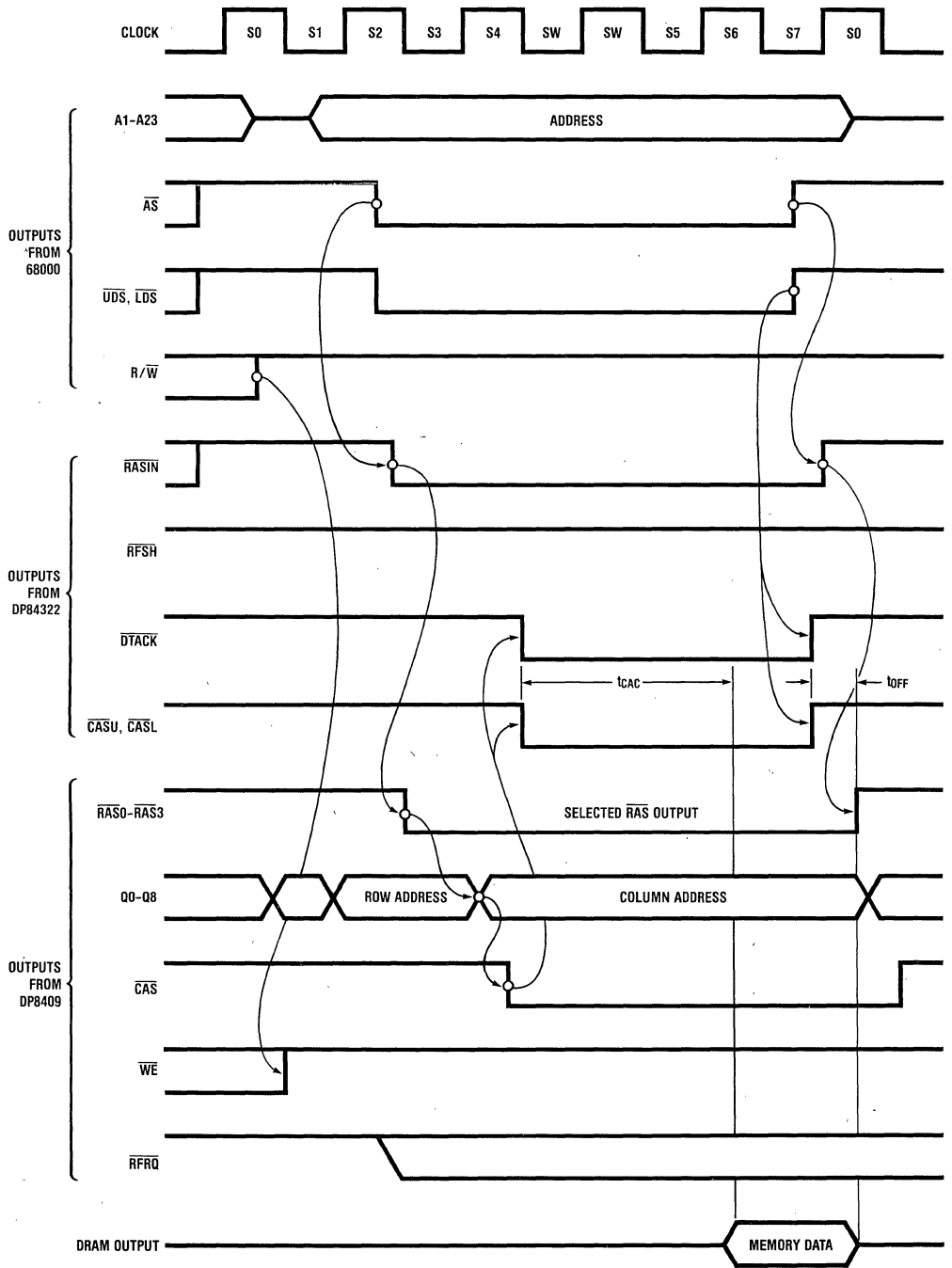
Timing Diagrams (Continued)

TAS Instruction Cycle (Wait = 0, Pin 5 = R/W)



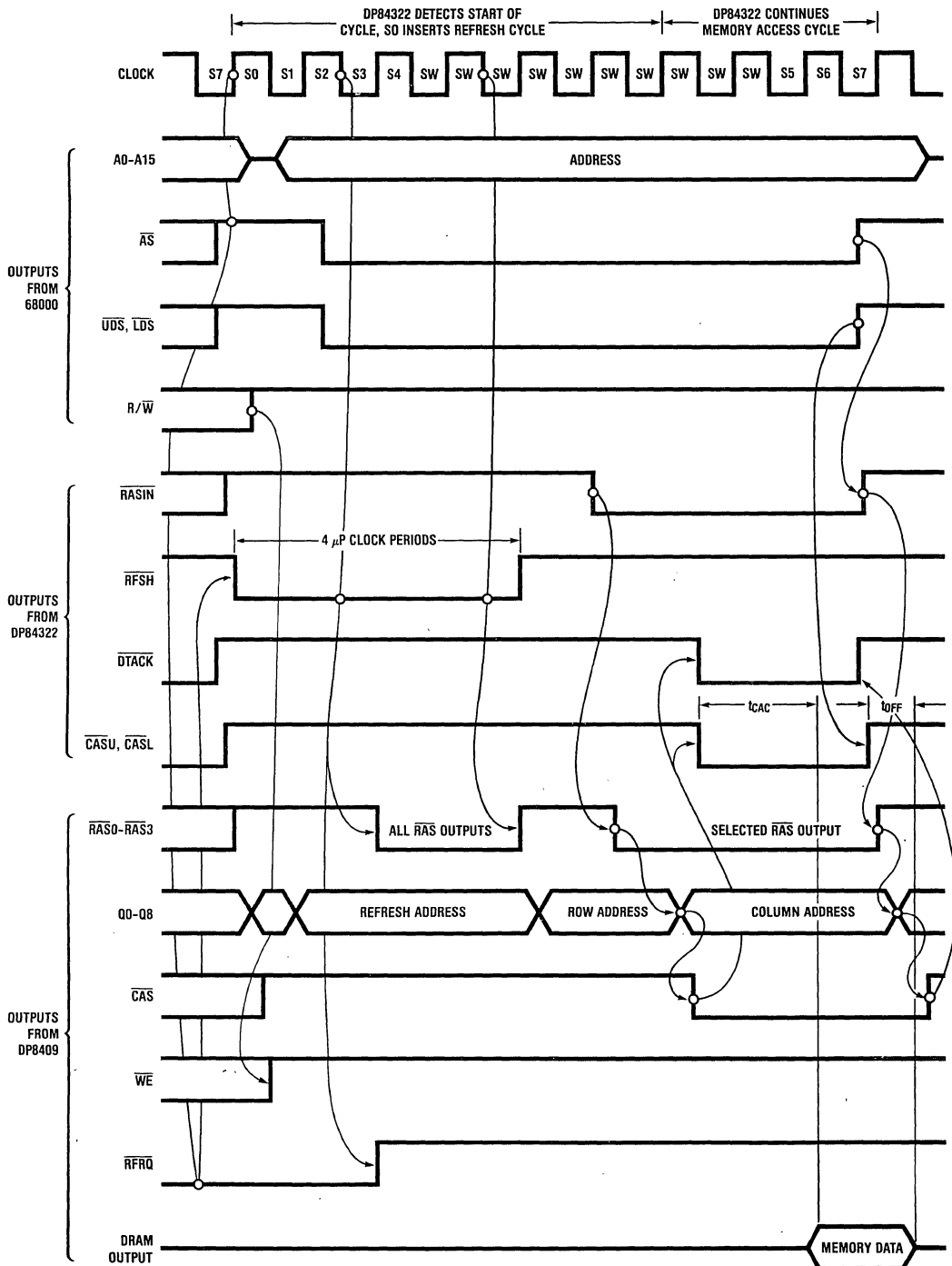
Timing Diagrams (Continued)

Memory Read Cycle (Wait = 1, Pin 5 = 0)



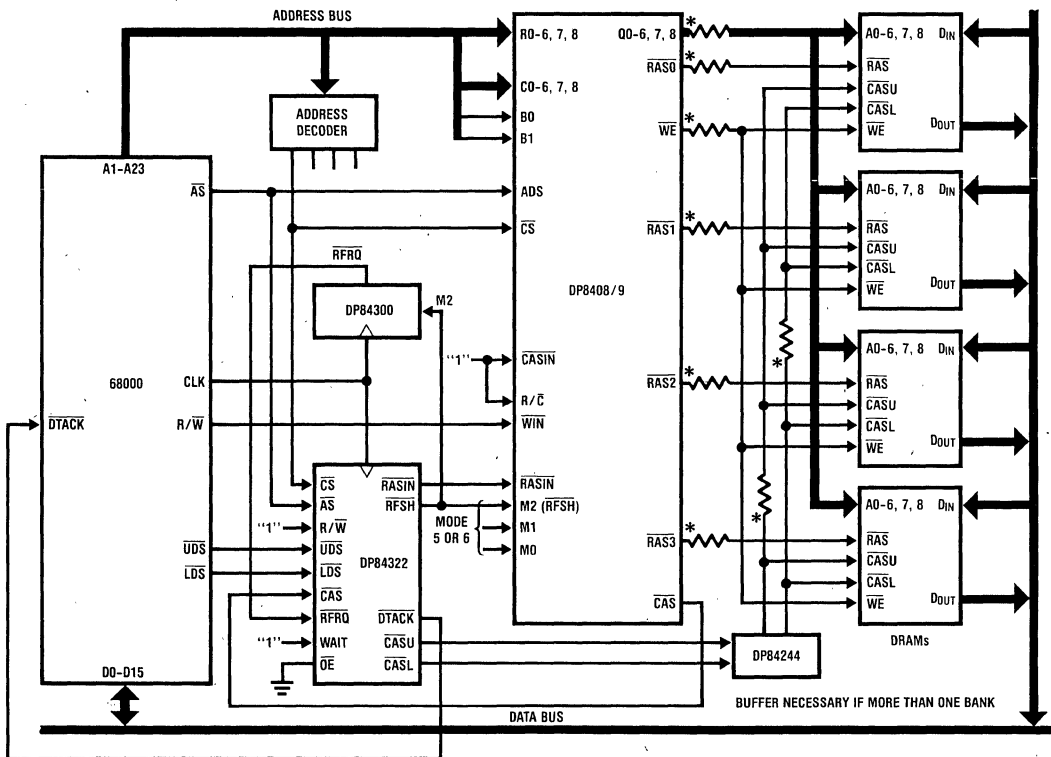
Timing Diagrams (Continued)

Memory Read Cycle and Forced Refresh (Wait = 1, Pin 5 = 0)



Modified System Block Diagram

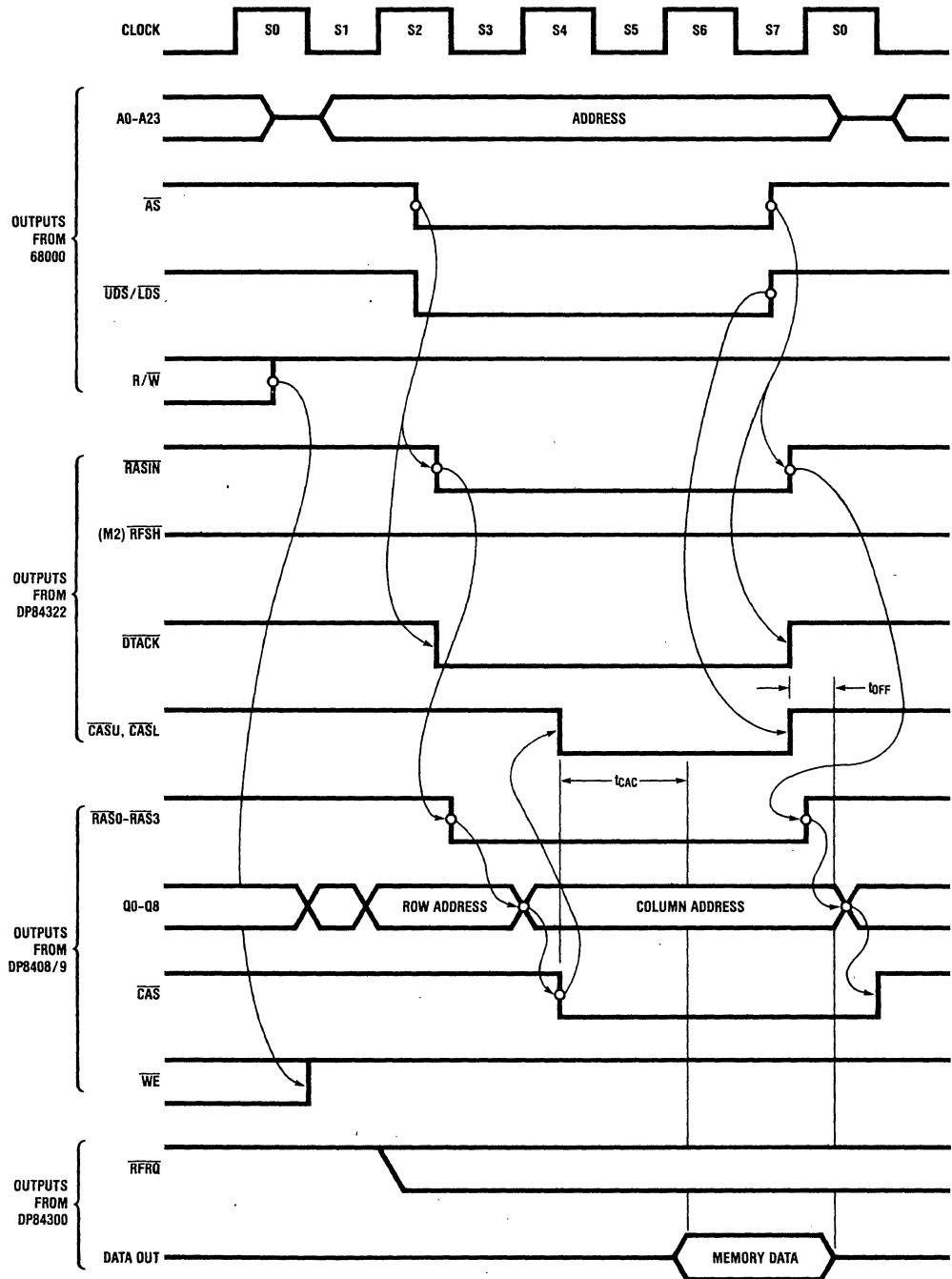
DP8408, DP8409 and 68000 Interface



*These outputs may need resistors.

Timing Diagrams (Continued)

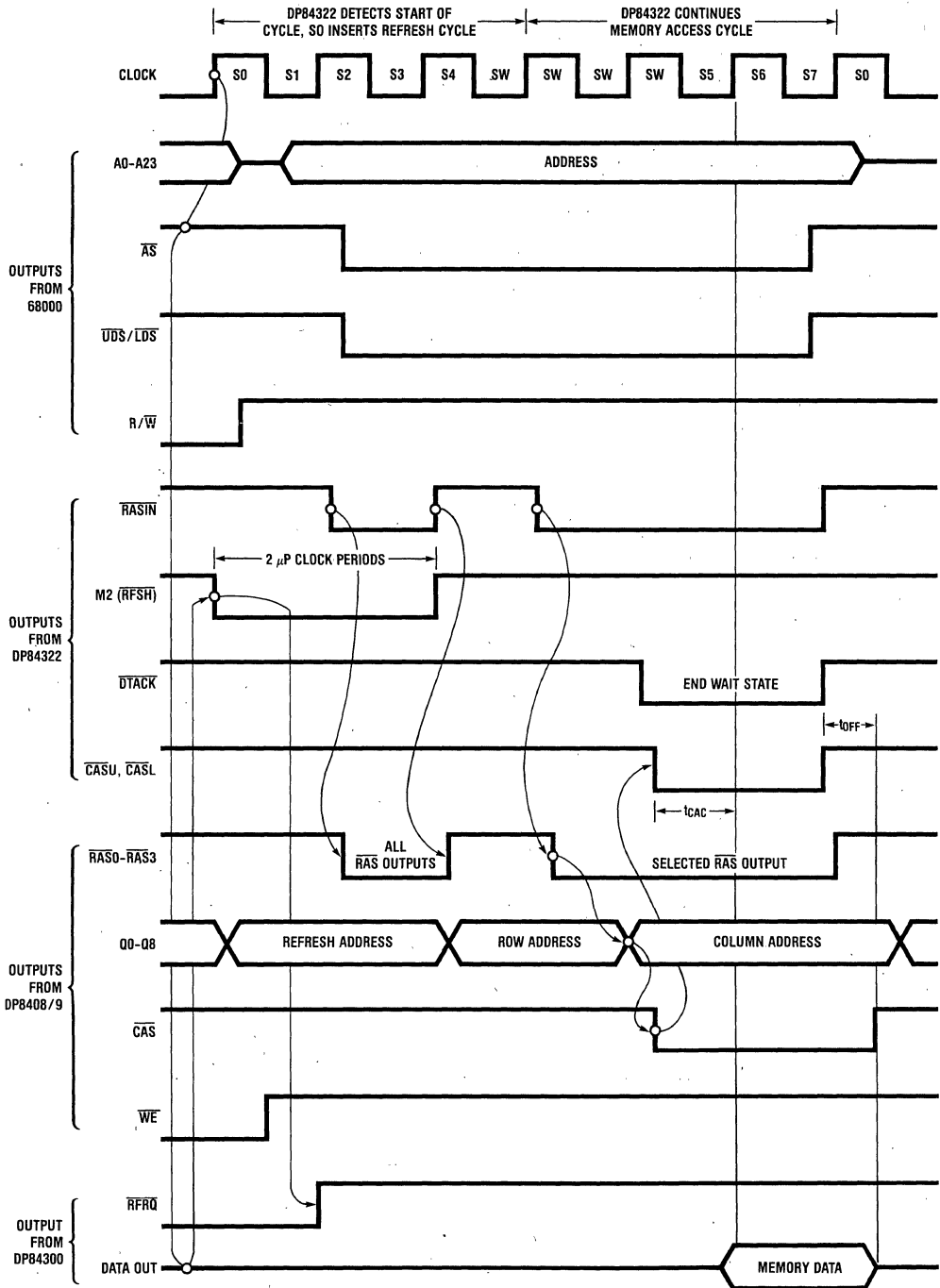
68000 Memory Read Cycle (Wait and Pin 5 = 1)



7

Timing Diagrams (Continued)

68000 Memory Read Cycle and Memory Refresh (Wait and Pin 5 = 1)



PAL16R4
DP84322
Dynamic RAM Controller Interface for the
MC68000-DP8409 Memory System
CK /AS /UDS /LDS R /RFRQ /CAS /CS WAIT GND
/OE /CL /CU /C /B /A /RFSH /DTACK /RASIN VCC

IF (VCC) RASIN = AS • /RFSH • /A +
RFSH • R • A • WAIT

IF (CS) DTACK = /R • CAS • WAIT +
UDS • /A • /B • /WAIT +
LDS • /A • /B • /WAIT +
AS • /R • /A • /B • /WAIT +
AS • /RFSH • R • /A • /B • WAIT

RFSH := /AS • RFRQ +
RFSH • /R • /C • WAIT +
RFSH • R • /A • WAIT +
RFSH • /C • /WAIT

A := RFSH

B := A

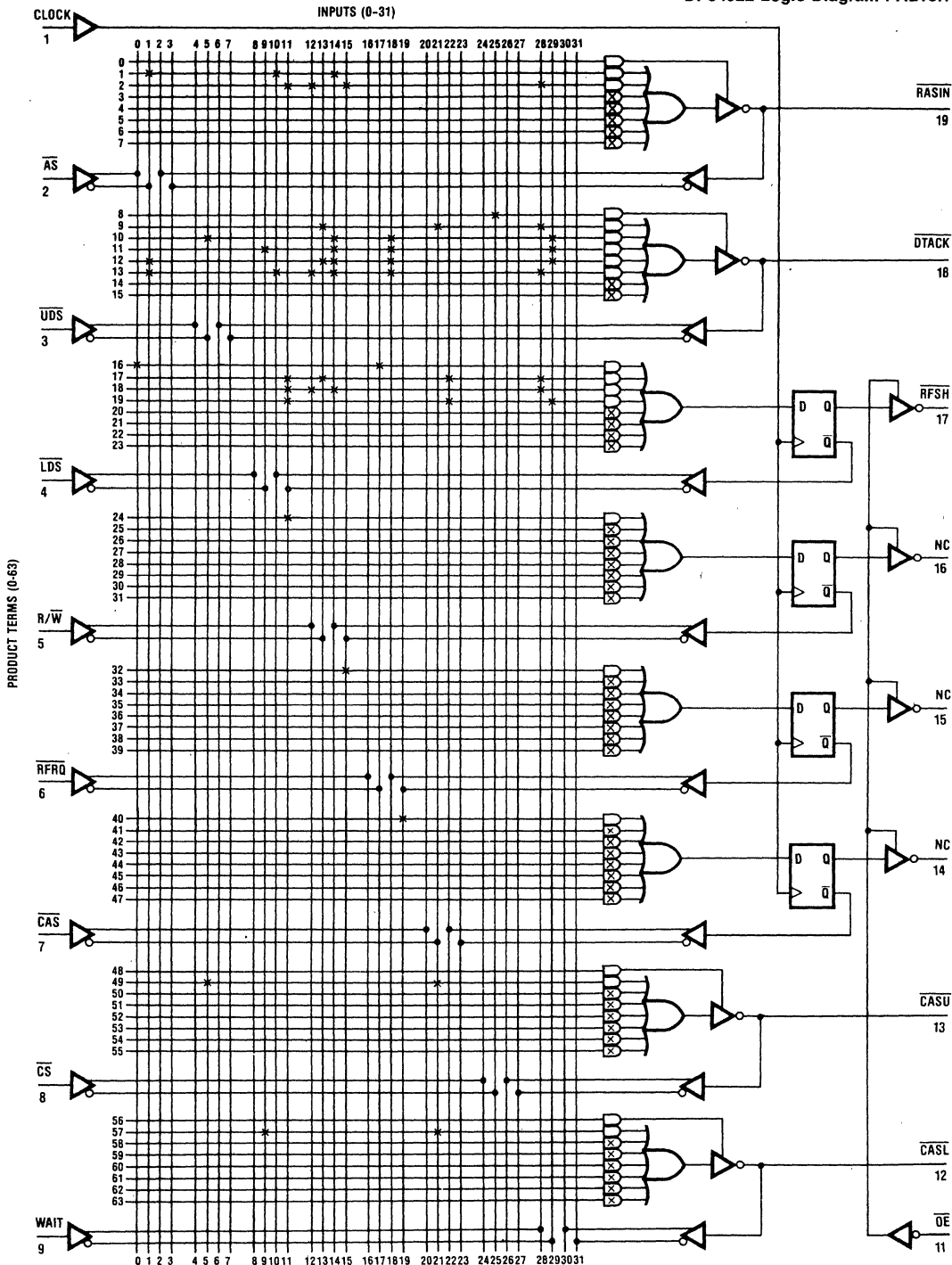
C := B

IF (VCC) CU = UDS • CDS

IF (VCC) CL = LDS • CAS

Function Table

CK	AS	UDS	LDS	R	RFRQ	CAS	CS	WAIT	OE	CL	CU	C	B	A	RFSH	DTACK	RASIN
C	H	L	L	H	H	H	H	L	L	H	H	X	X	X	X	X	H
C	H	L	L	H	H	L	H	L	L	L	L	X	X	X	X	X	H
C	H	L	H	H	H	L	H	L	L	H	L	X	X	X	X	X	H
C	H	H	L	H	H	L	H	L	L	H	H	X	X	X	X	X	H
C	H	H	H	H	H	H	H	L	L	H	H	H	H	H	H	Z	H
C	L	L	H	H	H	H	L	L	L	H	H	H	H	H	H	L	L
C	L	L	H	H	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	L	H	H	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	L	H	H	L	H	L	L	L	L	H	H	H	H	H	H	L	L
C	H	H	H	H	H	H	L	H	L	H	H	Z	Z	Z	Z	H	H



DP84332 Dynamic RAM Controller Interface Circuit for the 8086 and 8088 CPUs

General Description

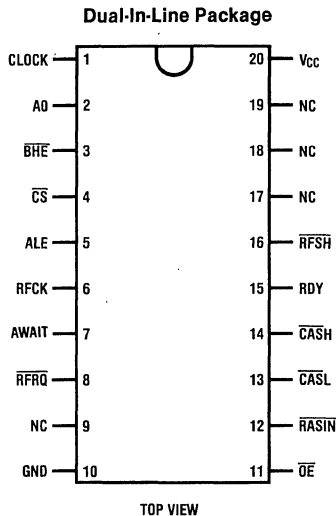
The DP84332 dynamic RAM controller interface is a Programmable Array Logic* (PAL) device which allows for easy interface between the DP8408 dynamic RAM controller and the 8086 and 8088 microprocessors. No wait states are required for memory access. Memory refreshing may be hidden (no wait states) or forced (up to three wait states).

The DP84332 supplies all the control signals needed to perform memory read, write, and refresh. Logic is also included to insert a wait state when using slow memory.

Features

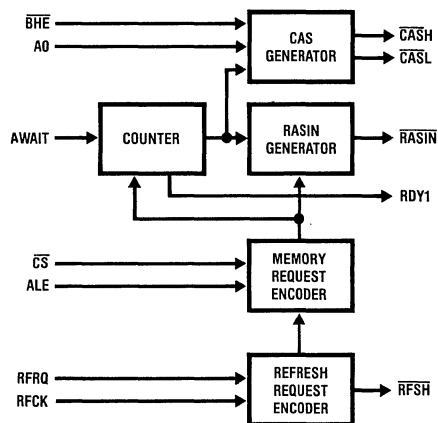
- Low parts count controller for the DP8408/DP8409
- Works with 8086 systems configured in min or max mode
- Performs hidden refresh using the DP8408 dynamic RAM controller
- Compatible with both the 8086 and 8088 microprocessors
- Capable of working at all CPU clock frequencies up to 8 MHz
- Standard National Semiconductor PAL part (DMPAL16R8)
- PAL logic equations can be modified by the user for his specific application and programmed into any of the PALs in the National Semiconductor family, including the new high speed PALs.

Connection Diagram



Order Number DP84322N-3
NS Package Number N20A

Block Diagram



TL/F/5000-2

*PAL is a registered trademark of Monolithic Memories, Inc.

Recommended Operating Conditions (Commercial)

	Min	Typ	Max	Units
V_{CC} , Supply Voltage	4.75	5.00	5.25	V
I_{OH} , High Level Output Current			-3.2	mA
I_{OL} , Low Level Output Current			24	mA
			(Note 2)	
T_A , Operating Free Air Temperature	0		75	°C

Electrical Characteristics over recommended operating temperature range

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	High Level Input Voltage		2			V
V_{IL}	Low Level Input Voltage				0.8	V
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}, I_I = -18 \text{ mA}$			-1.5	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}, V_{IH} = 2\text{V}, V_{IL} = 0.8\text{V}, I_{OH} = \text{Max}$	2.4			V
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}, V_{IH} = 2\text{V}, V_{IL} = 0.8\text{V}, I_{OL} = \text{Max}$			0.5	V
I_{OZH}	Off-State Output Current High Level Voltage Applied	$V_{CC} = \text{Max}, V_{IH} = 2\text{V}, V_O = 2.4\text{V}, V_{IL} = 0.8\text{V}$			100	μA
I_{OZL}	Off-State Output Current Low Level Voltage Applied	$V_{CC} = \text{Max}, V_{IH} = 2\text{V}, V_O = 0.4\text{V}, V_{IL} = 0.8\text{V}$			-100	μA
I_I	Input Current at Maximum Input Voltage	$V_{CC} = \text{Max}, V_I = 5.5\text{V}$			1.0	mA
I_{IH}	High Level Input Current	$V_{CC} = \text{Max}, V_I = 2.4\text{V}$			25	μA
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max}, V_I = 0.4\text{V}$			-250	μA
I_{OS}	Short Circuit Output Current	$V_{CC} = \text{Max}$	-30		-130	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max}$		150	225 (Note 1)	mA

DP84332-3 Switching Characteristics over recommended ranges of temperature and V_{CC}

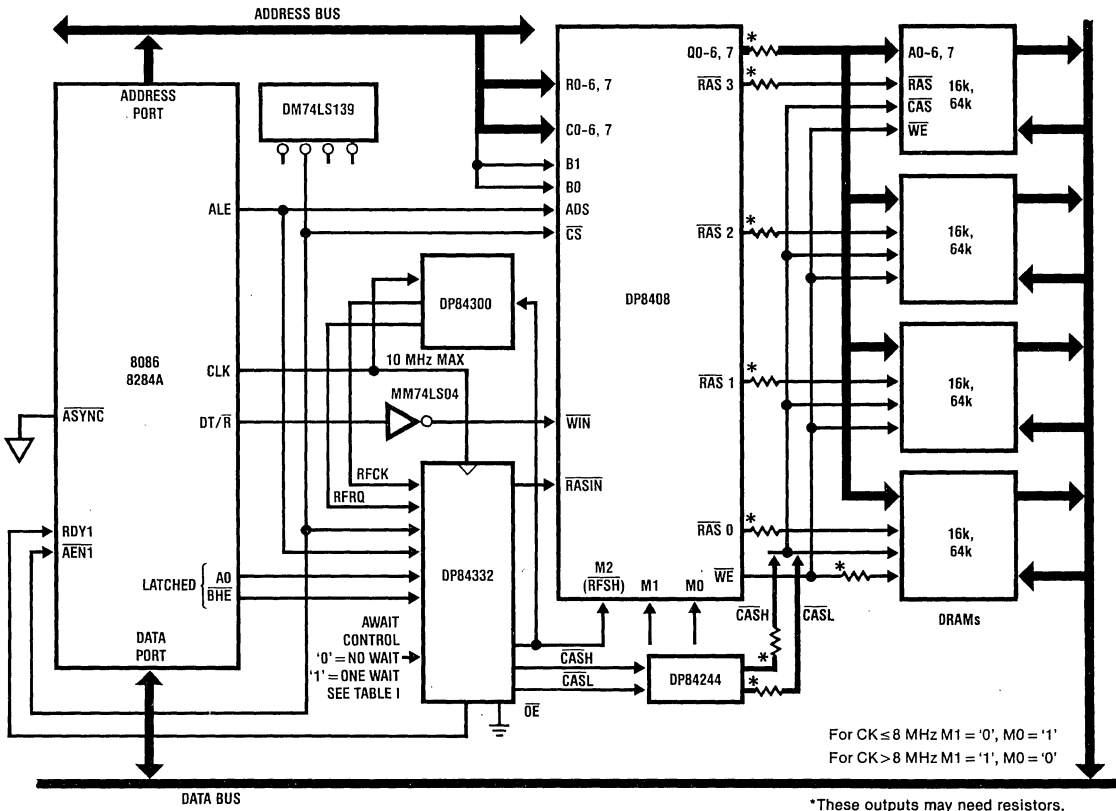
Symbol	Parameter	Conditions $R_L = 667\Omega$	Commercial $T_A = 0^\circ\text{C to } +75^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 5\%$			Units
			Min	Typ	Max	
t_{PD}	Clock to Output	$C_L = 45 \text{ pF}$		15	25	ns
t_{PZX}	Pin 11 to Output Enable	$C_L = 45 \text{ pF}$		15	25	ns
t_{PXZ}	Pin 11 to Output Disable	$C_L = 5 \text{ pF}$		15	25	ns
t_w	Width of Clock	High	25			ns
		Low	25			ns
t_{su}	Set-Up Time		40			ns
t_H	Hold Time		0	-15		ns

Note 1: $I_{CC} = \text{max}$ at minimum temperature.

Note 2: One output at a time; otherwise 16 mA.

System Block Diagram

Interfacing the DP8408 to an 8086 System



Mnemonic Description

INPUT SIGNALS

- CLOCK** The CLOCK signal determines the timing of the outputs and should be connected directly to the 8086 clock.
- A0, BHE** These inputs come from the 8086 CPU. They must remain stable during the memory cycle for proper operation of the CAS outputs.
- OE** Chip enable. This input is used to select the memory and enable the hidden refresh logic.
- ALE** Address latch enable. This input is used to indicate the beginning of a memory cycle.
- RFCK** Refresh clock. The period of this input determines the refresh interval. The duty cycle of this clock will determine the length of time that the circuit will attempt a hidden refresh.
- AWAIT** When connected to V_{CC} , the DP84332 will insert an extra wait state in selected memory cycles.
- RFRQ** Refresh request. This input requests the DP84332 to perform a refresh. The state of the RFCK input will determine what type of refresh will be performed.

OUTPUT SIGNALS

- RASIN** This output provides a memory cycle start signal to the DP8408, and provides RAS timing during refresh.
- CASH, CASL** These signals are the separate CASs needed for byte writing. Their presence is controlled by BHE and A0 respectively.
- RDY** This output is used to insert a wait state into the 8086 memory cycles when selected and during a forced refresh cycle where the 8086 attempts to access the memory. The 8284A clock circuit should be configured so that ASYNC is enabled.
- RFSH** This output controls the mode of the DP8408 dynamic RAM controller. When low, it switches the DP8408 into an all RAS refresh mode. This signal is also used to reset the refresh request logic.

Functional Description

A memory cycle starts when chip select (\overline{CS}) and address latch enable (ALE) are true. RASIN is supplied from the DP84332 to the DP8408 dynamic RAM controller, which then supplies a RAS signal to the selected dynamic RAM bank. After the necessary row address hold time, the DP8408 switches the address outputs to the column address. The DP84332 then supplies the required \overline{CAS} signals (\overline{CASH} , \overline{CASL}) to the RAM. For byte operations, only one \overline{CAS} will be activated. To differentiate between a read and a write, the DT/ \overline{R} signal from the CPU is inverted and supplied by the DP8408 to the memory array.

A refresh cycle is started by one of two conditions. One is when a refresh is requested (RFRQ is true), refresh clock (RFCK) is high, and a non-selected memory cycle is started (CE is not true, ALE is high). This is called hidden refresh because it is transparent to the CPU. In this case, the address supplied to the memories comes from the refresh counter in the DP8408, and no \overline{CAS} signals are generated from the DP84332. The second form of refresh occurs when a refresh is requested, refresh clock is low, and there is no memory cycle in progress. This is called forced refresh, because the CPU will be forced to wait during the next memory cycle to allow for the refresh to be performed. In this case, a refresh is performed as before, but any attempt to access memory is delayed by wait states until after the refresh is finished. In either case, the refresh request is cleared by the refresh line (\overline{RFSH}) which also goes to the DP8408.

In a standard memory cycle, the access can be slowed down by one clock cycle to accommodate slower memories. This extra wait state will not appear during the hidden refresh cycle, so faster devices on the CPU bus will not be affected.

With higher speed systems, memory speed requirements will affect the performance of the system. Table I shows memory speed requirements at three different CPU clock speeds.

TABLE I. MEMORY SPEED REQUIREMENTS

CPU Clock Frequency	t_{CAC}		t_{RAH}
	No Wait States	1 Wait State	
8 MHz	≤ 105 ns	≤ 223 ns	≤ 30 ns
5 MHz	≤ 170 ns	≤ 370 ns	≤ 30 ns

t_{CAC} = access time from \overline{CAS} including delay through buffers (DP84244)
 t_{RAH} = row address hold time from RAS

System Description

For memory operation, the DP84332 can be directly connected between the control signals from the CPU chip set and the DP8408 dynamic RAM controller. Each \overline{CAS} output of the DP84332 is capable of driving eight memory devices. If additional drive is required, a DP84244 buffer can be used to increase the fanout to the full capabilities of the DP8408 (eight memories per output of the DP84244).

The 84332 is a standard National Semiconductor PAL part (DMPAL16R8). The user can modify the PAL equations to support his particular application. The 84332 logic equations, function table (functional test) and logic diagram can be seen at the end of this data sheet.

Refresh Request Logic

To generate the refresh request for the DP84332, external circuitry is required. Figure 1 shows how this can be implemented, using standard SSI and MSI logic. A DM74LS393 counter is used to time the period between refresh cycles, while the DM74LS74 flip-flop is used to record the need of a new refresh. A better solution is to use the 24-pin DP84300 programmable refresh timer, as shown in Figure 2. This part allows a maximum amount of time for a hidden refresh to occur before lowering the refresh clock output, and implements the refresh request logic.

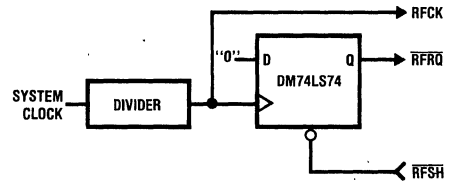


FIGURE 1. Using a Flip-Flop and a Counter for Refresh Request Logic

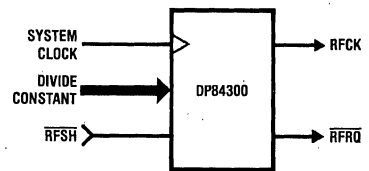
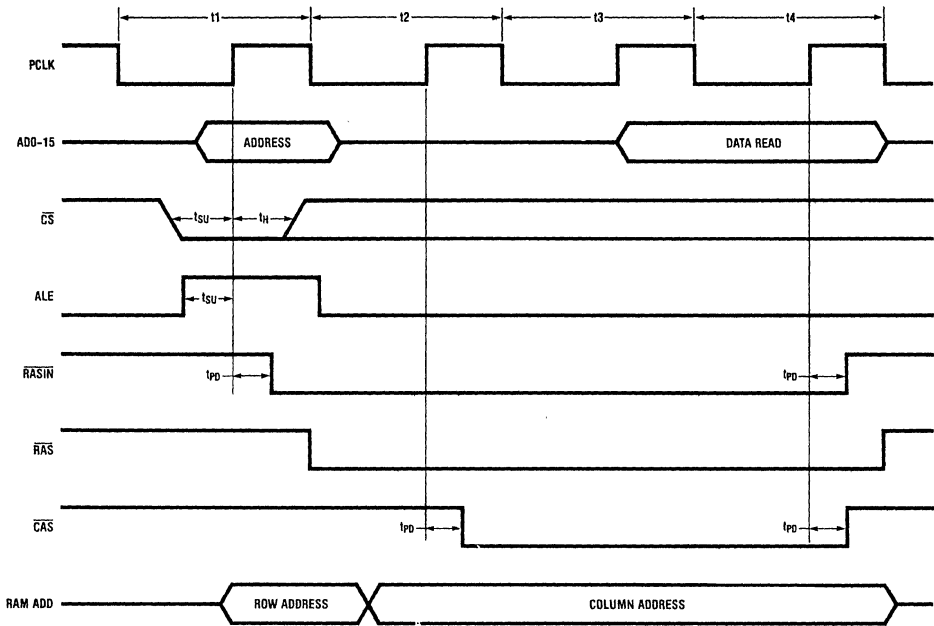


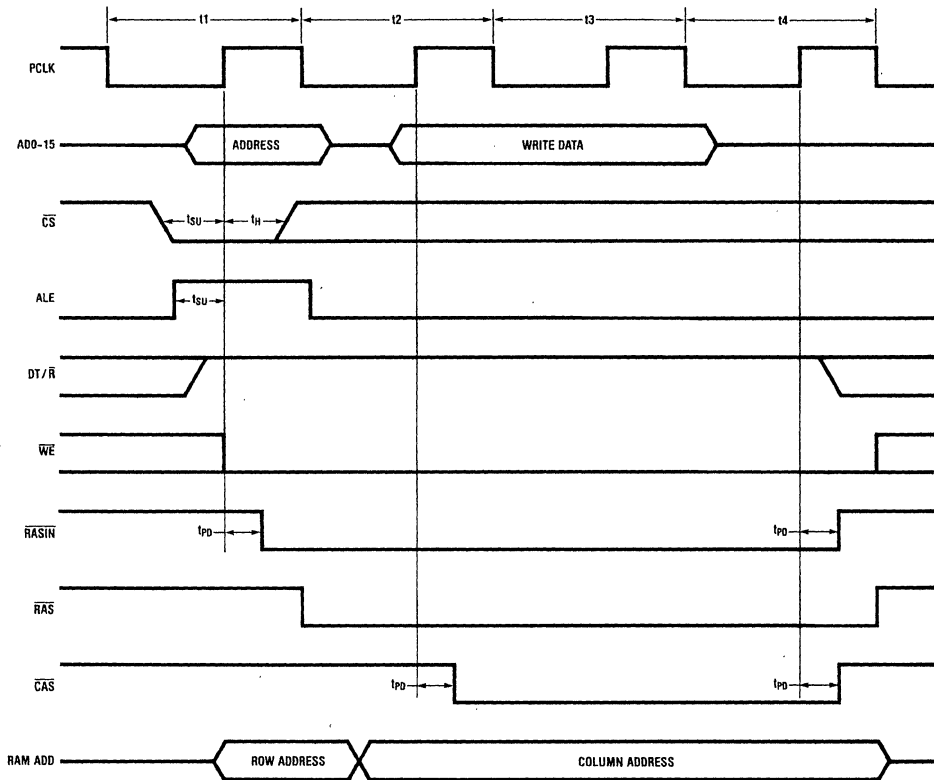
FIGURE 2. Using the DP84300 Refresh Counter for Refresh Request Logic

Timing Diagrams

Read Timing

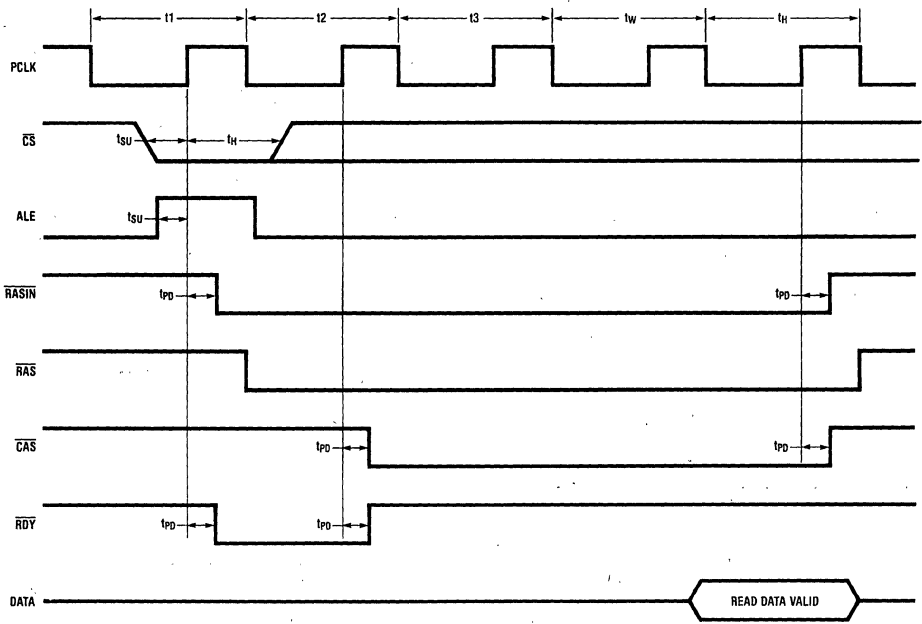


Write Timing

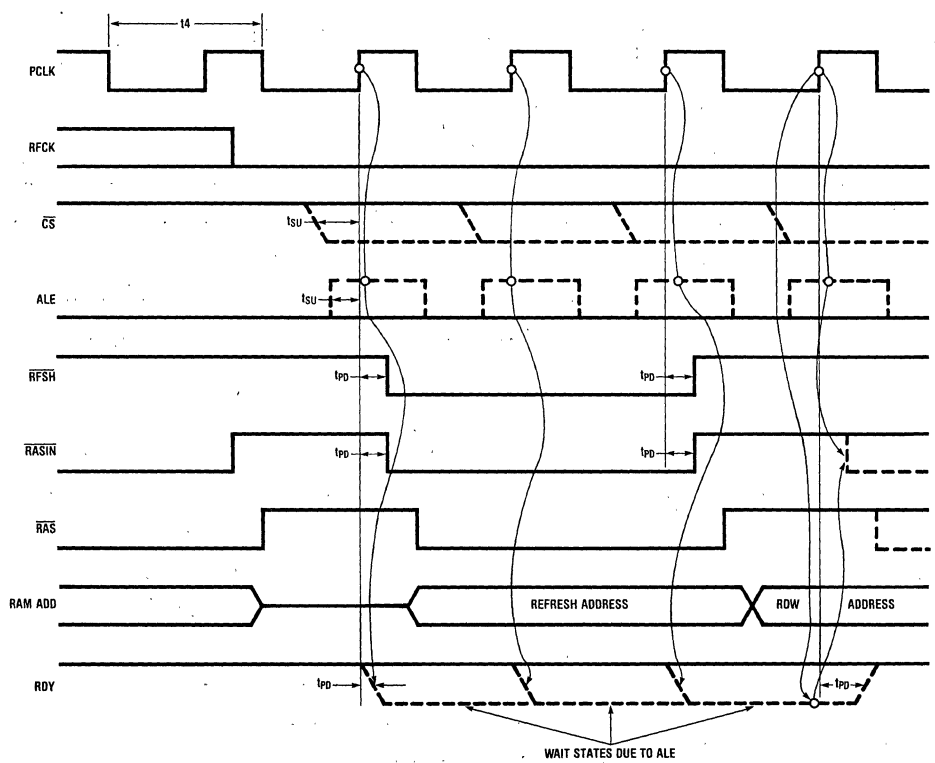


Timing Diagrams (Continued)

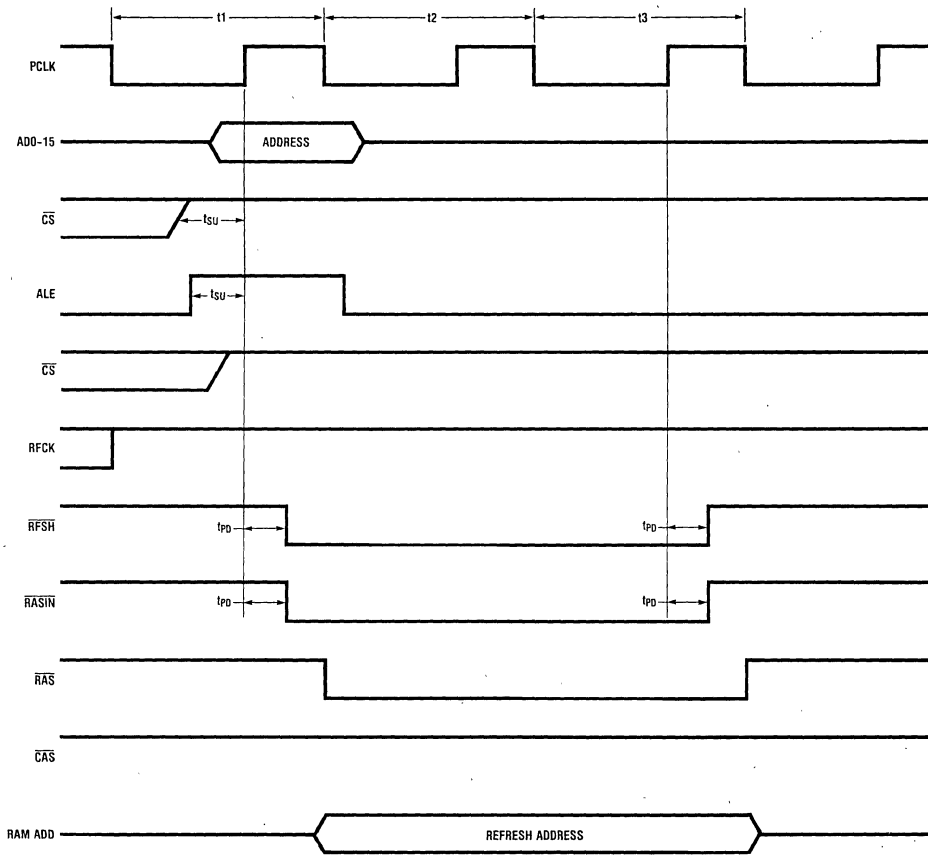
Memory Cycle with 1 Wait State



Forced Refresh



Transparent Refresh



16R8

DP84332

Dynamic RAM Controller Interface for the 8086-8408 System

CK A0 /BHE /CS ALE RFCK WAIT /RFRQ NC GND /OE /RASIN /CA /CB

RDY /RFSH /A /B /MRQ VCC

MRQ: = /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /MRQ • RFRQ • CS • ALE • /RFCK +
 MRQ • RASIN +
 RASIN • /CA • /CB • RDY • RFSH • /A • /MRQ • CS • ALE

B: = RASIN • /CA • /CB • RFSH • /A • /B +
 RASIN • /CA • /CB • /RDY • /RFSH • /A • /B • WAIT +
 RASIN • RDY • /RFSH • A • /B

A: = RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /WAIT +
 RASIN • RDY • /RFSH • /A • B +
 RASIN • RDY • /RFSH • A • /B

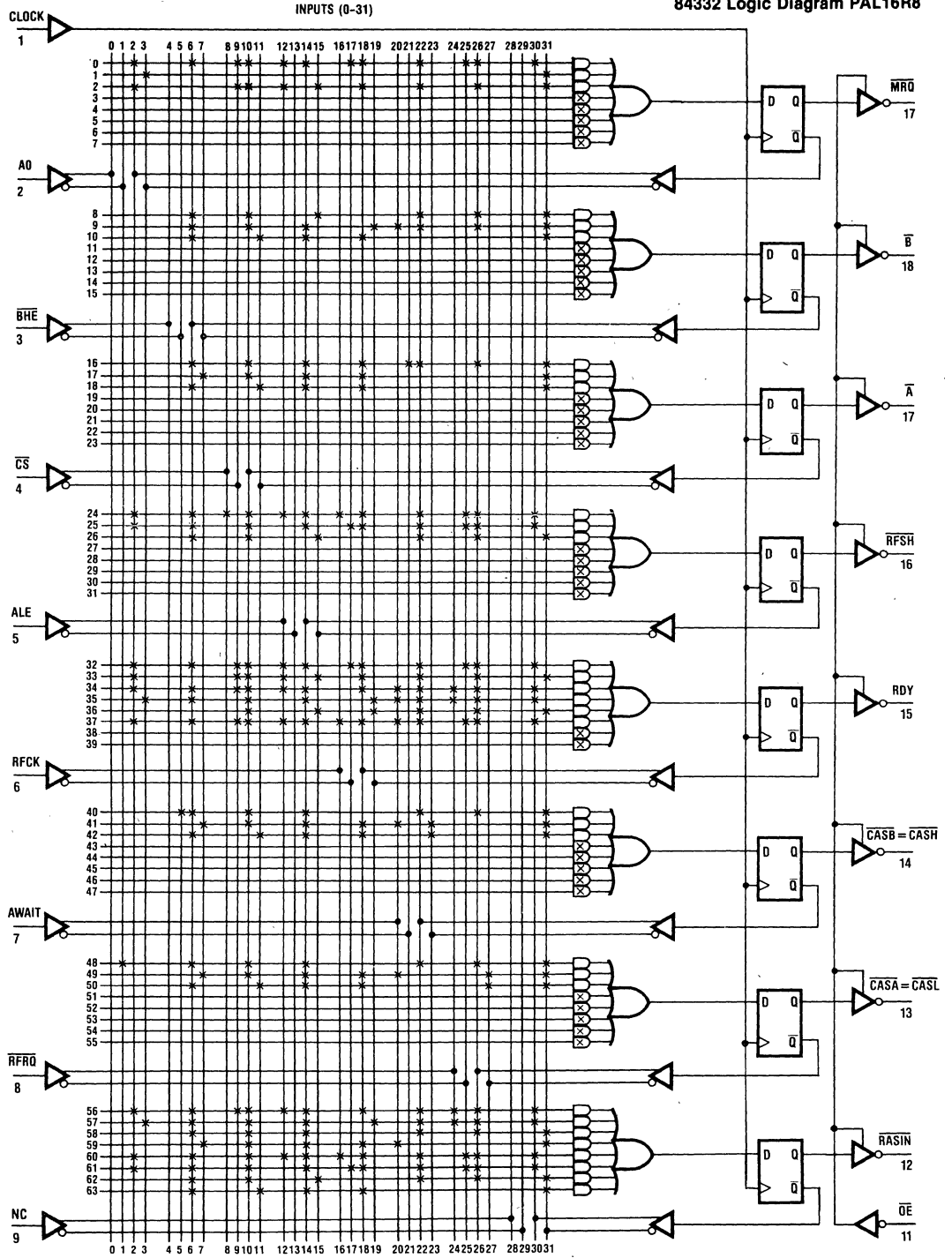
RFSH: = /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /MRQ • RFRQ • /CS • ALE • RFCK +
 /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /MRQ • RFRQ • /RFCK +
 RASIN • /CA • /CB • RFSH • /A • /B

/RDY: = /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • MRQ • RFRQ • CS • ALE • /RFCK +
 RASIN • /CA • /CB • RDY • RFSH • /A • /MRQ • CS • ALE +
 /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /MRQ • /RFRQ • CS • ALE • WAIT +
 /RASIN • /CA • /CB • /RDY • /RFSH • /A • /B • MRQ • /RFRQ • WAIT +
 RASIN • /CA • /CB • /RDY • RFSH • /A +
 /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /MRQ • RFRQ • CS • ALE • RFCK • WAIT

CB: = RASIN • /CA • /CB • /RFSH • /A • /B • BHE +
 RASIN • CB • RDY • /RFSH • /A • B • WAIT +
 RASIN • CB • RDT • /RFSH • A • /B

CA: = RASIN • /CA • /CB • /RFSH • /A • /B • /A0 +
 RASIN • CA • RDY • /RFSH • /A • B • WAIT +
 RASIN • CA • RDY • RFSH • A • /B

RASIN: = /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /MRQ • /RFRQ • CS • ALE +
 /RASIN • /CA • /CB • /RDY • /RFSH • /A • /B • MRQ • /RFRQ +
 RASIN • /CA • /CB • /RFSH • /A • /B +
 RASIN • RDY • /RFSH • /A • B • WAIT +
 /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /MRQ • RFRQ • ALE • RFCK +
 /RASIN • /CA • /CB • RDY • /RFSH • /A • /B • /MRQ • RFRQ • /RFCK +
 RASIN • /CA • /CB • RFSH • /A • /B +
 RASIN • RDY • /RFSH • A • /B



8086 PAL

Interfacing the DP8408/09 To Various Microprocessors

National Semiconductor
Application Note AN-309
Chuck Pham
June 1982



High storage density and low cost have made dynamic RAMs the designer's choice in most memory applications. However, the major drawback of dynamic RAMs is the complex timing involved. First, a $\overline{\text{RAS}}$ must occur with the row address previously set up on the multiplexed address bus. After the row address has been held for some minimum time after $\overline{\text{RAS}}$ (namely the row address hold time of the dynamic RAMs, t_{RAH}), the column address is set up and then $\overline{\text{CAS}}$ occurs. In addition, refreshing must be done periodically to keep all memory cells charged.

With the introduction of the DP8408 Dynamic RAM Controller/Driver, the above complexities are simplified. The DP8408 is housed in a 48-pin package with eight multiplexed address outputs (Q0-7) and six control outputs ($\overline{\text{RAS0-3}}$, $\overline{\text{CAS}}$, $\overline{\text{WE}}$). It consists of two 8-bit address latches and an 8-bit refresh counter. All the output drivers are capable of driving 500pF loads.

The following discussion demonstrates a typical application of the DP8408 Dynamic RAM Controller/Driver in Z8000™ and Z80®-based systems. The DP8408 basically has six modes of operation: Externally Controlled Refresh, Externally Controlled All- $\overline{\text{RAS}}$ Write, Externally Controlled Access, Auto Access (slow t_{RAH}), Auto Access (fast t_{RAH}) and Set End of Count.

The DP8408, operating in the auto access mode, requires only $\overline{\text{RASIN}}$ to initiate a memory access cycle because all the dynamic RAM's control signals are automatically delayed from this input. (Refer to *Figure 1* for the auto access timing sequence.)

In the following applications, the DP8408 operates in either mode 5 or mode 6 Auto Access and mode 1 or 2 Externally Controlled Refresh to provide minimum additional logic.

The DP8408 and Z8000 Interface

Memory Access Cycle:

Figure 2a shows the detailed block diagram of the Z8000 and the DP8408 interface. Consider a memory cycle of the Z8000; first, the memory address is output on the Address and Data multiplexed bus (AD0-15) during T1 and is latched to the DP8408 by $\overline{\text{AS}}$. Simultaneously, $\overline{\text{MREQ}}$ goes low and is used to provide $\overline{\text{RASIN}}$ to initiate a memory transaction cycle. Then the selected $\overline{\text{RAS}}$ output, row address hold time (t_{RAH}), column address set up time (t_{ASC}) and $\overline{\text{CAS}}$ output will follow $\overline{\text{RASIN}}$ as determined by the auto access modes. A maximum of one wait state is required for 6MHz and 10MHz CPUs. This wait state is automatically inserted by the $\overline{\text{CAS}}$ output of the DP8408. For systems using byte-writing, the DM74S158 provides two separate $\overline{\text{CAS}}$ outputs for ac-

cessing the low and high byte of memory. Note that $\overline{\text{DS}}$ from the Z8000 is also gated with the DP8408's $\overline{\text{CAS}}$ output to generate $\overline{\text{CASL}}$ and $\overline{\text{CASH}}$. This guarantees the valid data from the Z8000 being written into memory during memory write cycles. Refer to *Figure 3* for the detailed memory transaction cycle timing.

The following formula allows the designer to determine the proper memory speed in terms of t_{CAC} (access time from $\overline{\text{CAS}}$):

$$t_{\text{CAC max.}} = 3 \times t_{\text{CC}} - t_{\text{dc(MR)}} - t_{\text{R1CL}} - t_{\text{CASdly}} - t_{\text{sDR(C)}} - 15.$$

The Z8000 parameters:

- t_{CC} : clock cycle time
- $t_{\text{sDR(C)}}$: read data to clock \uparrow set up time
- $t_{\text{dc(MR)}}$: clock to $\overline{\text{MREQ}}$ delay

The DP8408, 74S158 and 74LS245 parameters:

- t_{R1CL} : RASIN to $\overline{\text{CAS}}$ delay
- t_{CASdly} : the propagation delay of the 74S158
- 15 ns: the propagation delay of the 74LS245 (at 50pF load)

For the 10MHz CPU and the DP8408:

- $t_{\text{CAC max.}} = 300 - 40 - 131 - 14 - 10 - 15 = 90 \text{ ns.}$
- $t_{\text{R1CL max.}}$ (mode 6) = 131 ns at 15pF load.
- $t_{\text{CASdly max.}} = 14 \text{ ns at } 50 \text{ pF load.}$

Since $\overline{\text{MREQ}}$ is connected directly to $\overline{\text{RASIN}}$, t_{RP} ($\overline{\text{RAS}}$ precharge time) and t_{RAS} ($\overline{\text{RAS}}$ pulse width) are determined by $\overline{\text{MREQ}}$ high and low, respectively.

Memory Refresh Cycle:

The Z8000 CPU contains a refresh rate counter for automatic memory refresh. This counter should be programmed during the processor initialization to determine the refresh rate. Since memory refresh is automatically inserted by the Z8000, there is no additional refresh arbitration logic allowed. The CPU's STATUS 3 (ST3) output can be directly connected to the M2 (RFSH) pin of the DP8408. During the memory refresh cycle, ST3 goes low, setting the DP8408 in the external control refresh mode (mode 2). Then all four $\overline{\text{RAS}}$ outputs will follow $\overline{\text{MREQ}}$ to strobe the DP8408's refresh address to all memory banks (the Z8000 refresh address is ignored). As $\overline{\text{MREQ}}$ goes high again, the DP8408 increments its refresh counter, preparing it for the next refresh cycle. Refer to *Figure 4* for the refresh cycle timing. Note that ST3 also goes low during the internal cycle, I/O reference cycle and interrupt acknowledge cycle, but the memory will not be refreshed because $\overline{\text{MREQ}}$ is not active during these cycles. The DP8408 on-chip refresh counter will not be incremented when M2 goes low unless $\overline{\text{MREQ}}$ is inserted.

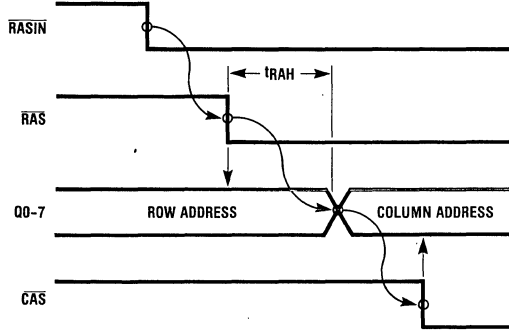


Figure 1. Auto Access Timing Sequence (Mode 5 or Mode 6)

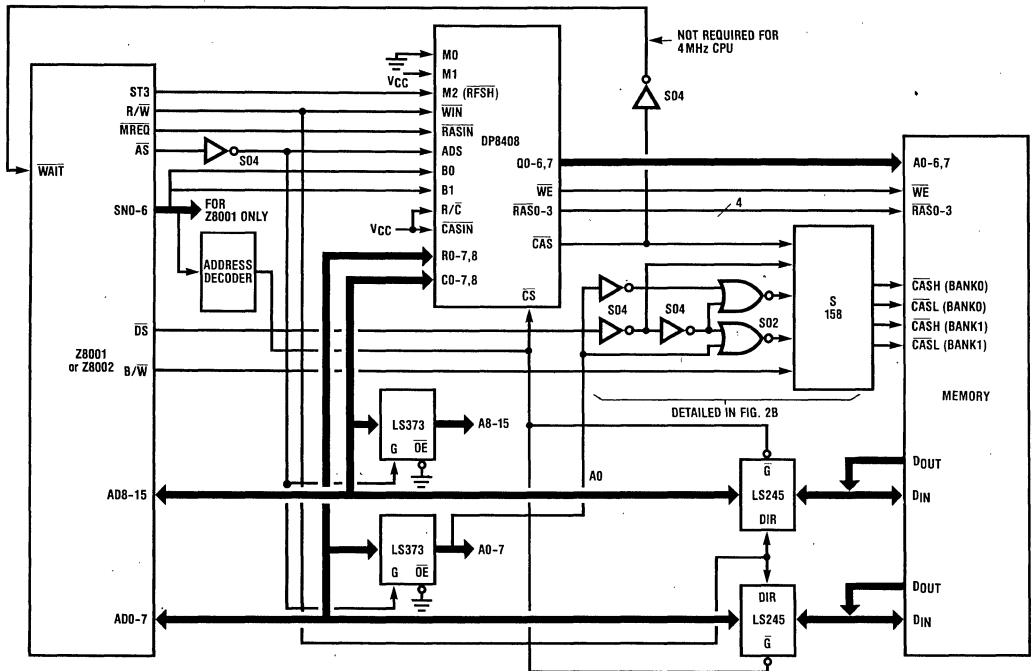


Figure 2a. Z8000 and DP8408 Interface

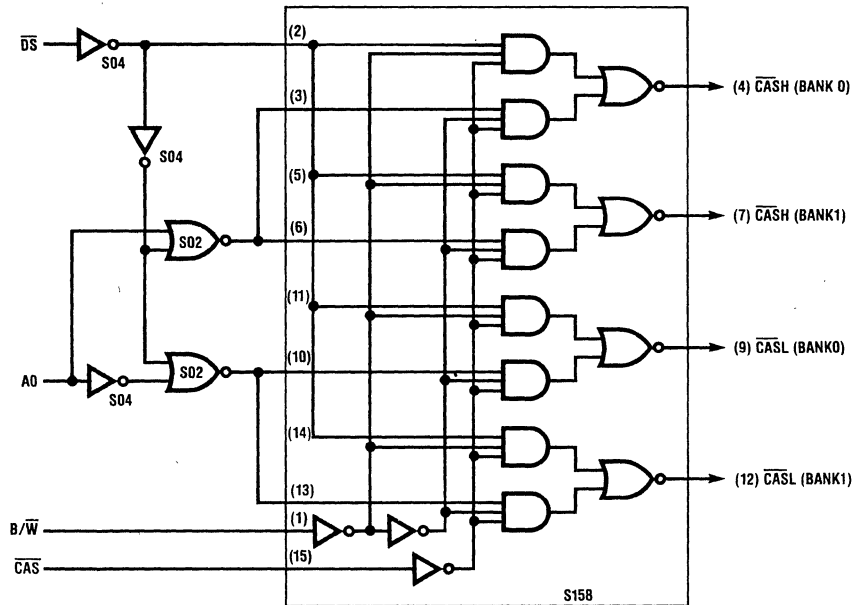


Figure 2b. CASH and CASL Decoder

When the processor is in either halt state (by executing the privileged HALT instruction) or single-stepping mode (when STOP input is low), it introduces memory refresh cycles. However, care should be taken when the CPU is in either a WAIT state or a Bus Acknowledge cycle, that the dynamic RAM refresh will not take place. If these conditions occur over a long period of time, a burst refresh is recommended. This can be done by toggling RASIN while keeping M2 low, until all the rows of the dynamic RAM have been refreshed, then the CPU can resume its operations.

The DP8408 and Z80A® Interface

Instruction Fetch Cycle:

Figure 5 shows the detailed interconnections between the DP8408, the Z80® and the Dynamic RAMs. Figure 6 shows the timing during an M1 cycle (op code fetch). The program counter is output on the address bus at the beginning of the M1 cycle. One-half clock later, MREQ goes active. This input is used to provide RASIN to the DP8408 to access the dynamic memory. Subsequently,

the selected RAS output, Row to Column Select and then CAS output will automatically follow RASIN as determined by the Auto Access modes of the DP8408. The RD line also goes active to indicate a memory read cycle is in progress. After t_{CAC} (access time from CAS), read data becomes valid. This data is sampled on the rising edge of T3, then both MREQ and RD go inactive. Immediately following this, RFSH goes low, putting the DP8408 in the Externally Controlled Refresh mode. The MREQ goes active causing all four RAS outputs to go active to perform a refresh to all the banks of the dynamic RAMs. Note that during memory refresh cycles, the refresh address from the CPU is output on the address bus. However, the contents of the DP8408 on-chip refresh counter are used instead to provide the row address to the dynamic memory array. Since the Z80 provides only a 7-bit refresh address, it is an advantage to use the DP8408 8-bit refresh counter to support 64k dynamic RAMs directly. The DP8408 refresh counter is incremented as MREQ returns high, ending the memory refresh. The RFSH goes inactive returning the DP8408 back to the Auto Access mode, preparing it for the next access cycle.

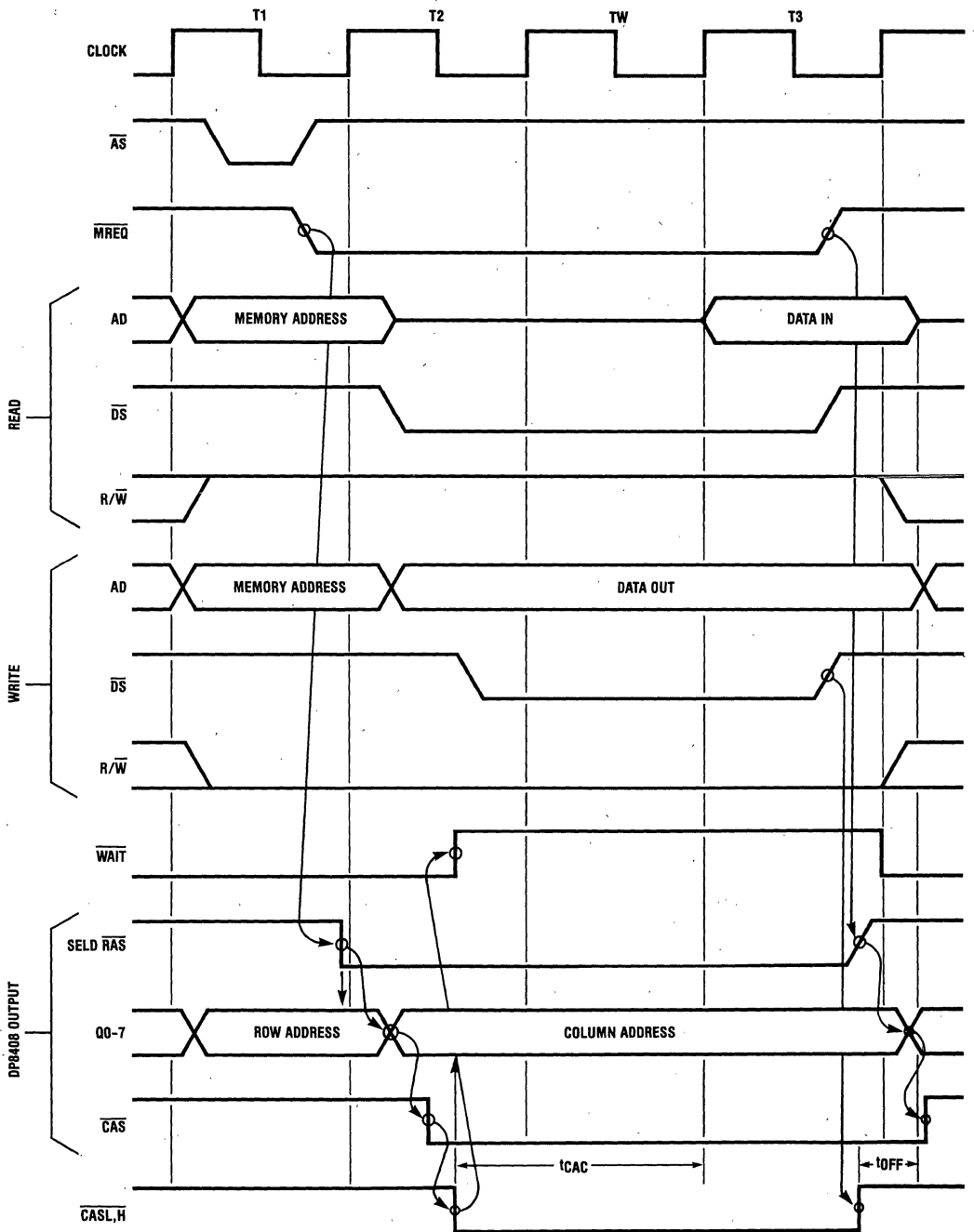


Figure 3. Memory Transaction Cycles

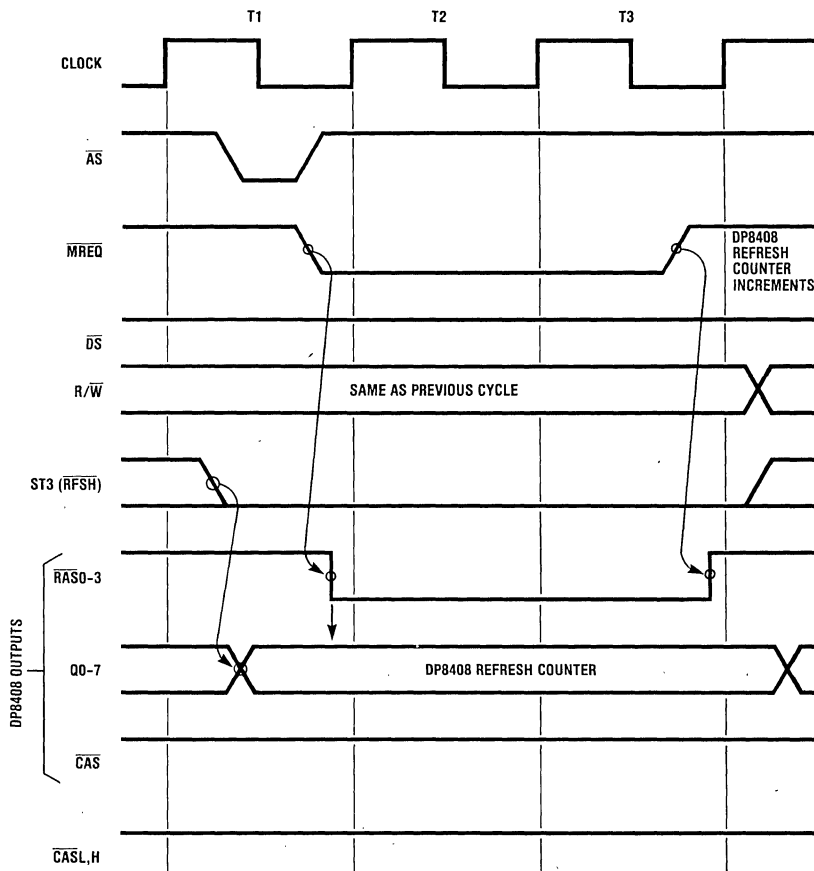


Figure 4. Memory Refresh Cycle

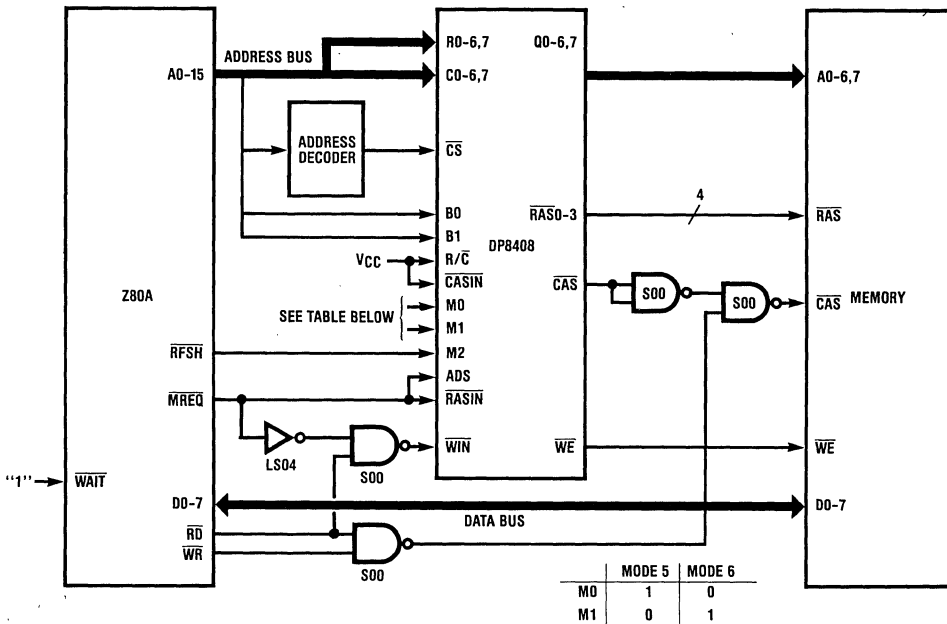


Figure 5. DP8408 and Z80A Interface

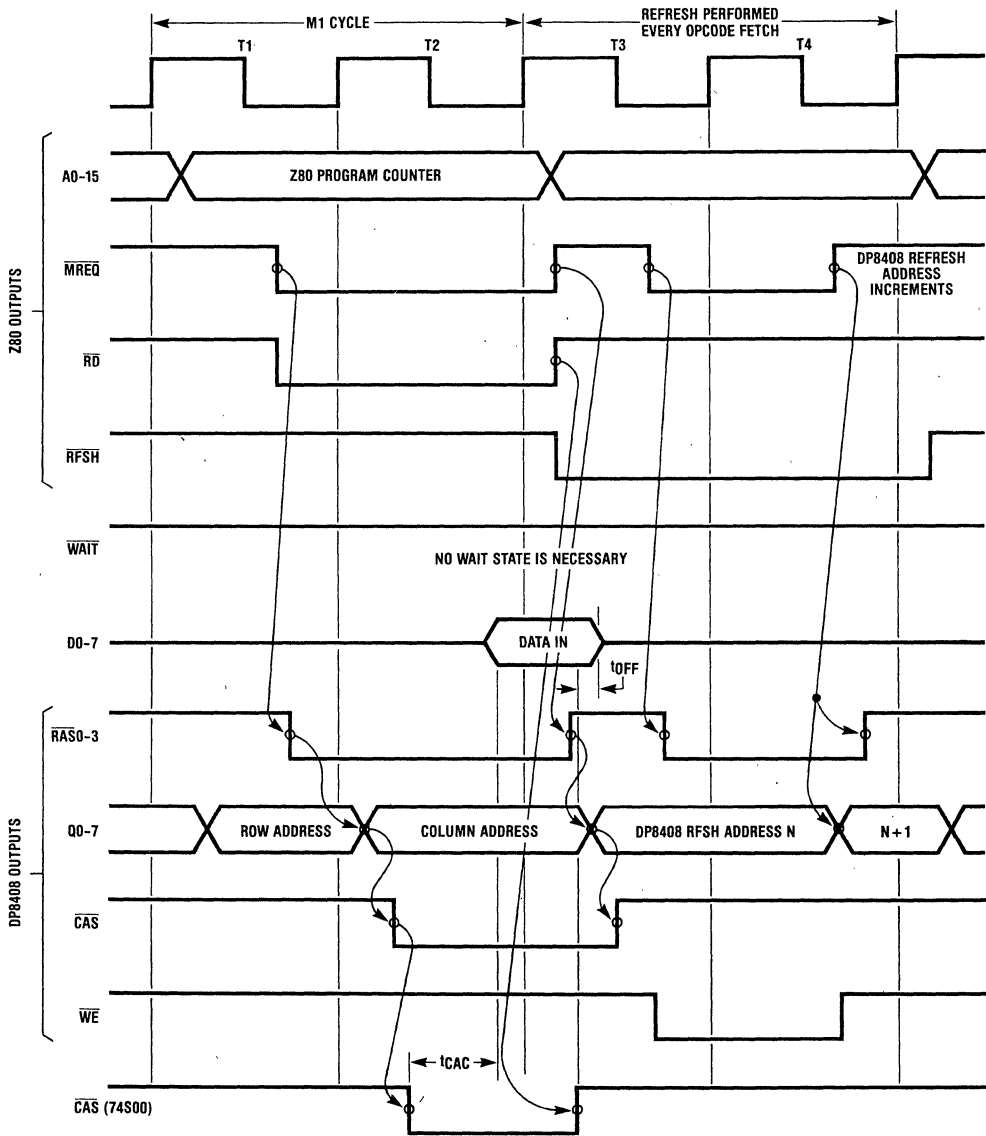


Figure 6. Z80A Op Code Fetch Cycle Showing Memory Refresh

Memory Access Cycle:

Figure 7 shows the timing of the memory read and memory write cycle other than for the M1 op code fetch cycle. Similar to the op code fetch cycle, \overline{MREQ} is used to provide \overline{RASIN} . \overline{MREQ} goes active after the address to the memory has had time to stabilize. Again, \overline{RAS} output, Row to Column Select and then \overline{CAS} output will automatically follow \overline{RASIN} to access the specified memory location. For a memory read cycle, both \overline{MREQ} and \overline{RD} go active, and as a result, \overline{WIN} remains high (refer to Figure 5), which allows a memory read operation to occur. On the other hand, only \overline{MREQ} goes active during a write cycle, which forces \overline{WIN} low, indicating an early write cycle. It should be noted that the \overline{CAS} output to the memory array will not go low until \overline{WR} goes low during memory write cycles as this guarantees the valid CPU data will be written into memory.

It is worth mentioning that the Z80 CPU provides powerful block transfer instructions. An example is the LDIR (load, increment and repeat); using only this instruction, the programmer can move any block of data from the

location pointed to by the D and E registers. This operation is repeated until the byte counter (B and C registers) reaches zero. Thus, this single instruction can move any block of data from one location to any other. Due to the fact that this instruction is refetched after each data byte transfer, the memory refresh cycle always takes place even though a transfer of up to 64k bytes of data may be performed. Furthermore, when the CPU has executed the software HALT instruction and is waiting for an interrupt before normal CPU operations can resume, the CPU executes NOP instructions to maintain memory refresh activity.

However, care should be taken when the CPU is in either WAIT state or a Bus Acknowledge cycle, the dynamic RAM refresh will not take place. If these conditions occur long enough, a burst refresh is recommended, and it can be done by toggling \overline{RASIN} while keeping M2 low until all the rows of the dynamic RAM have been refreshed before the CPU can resume its operation.

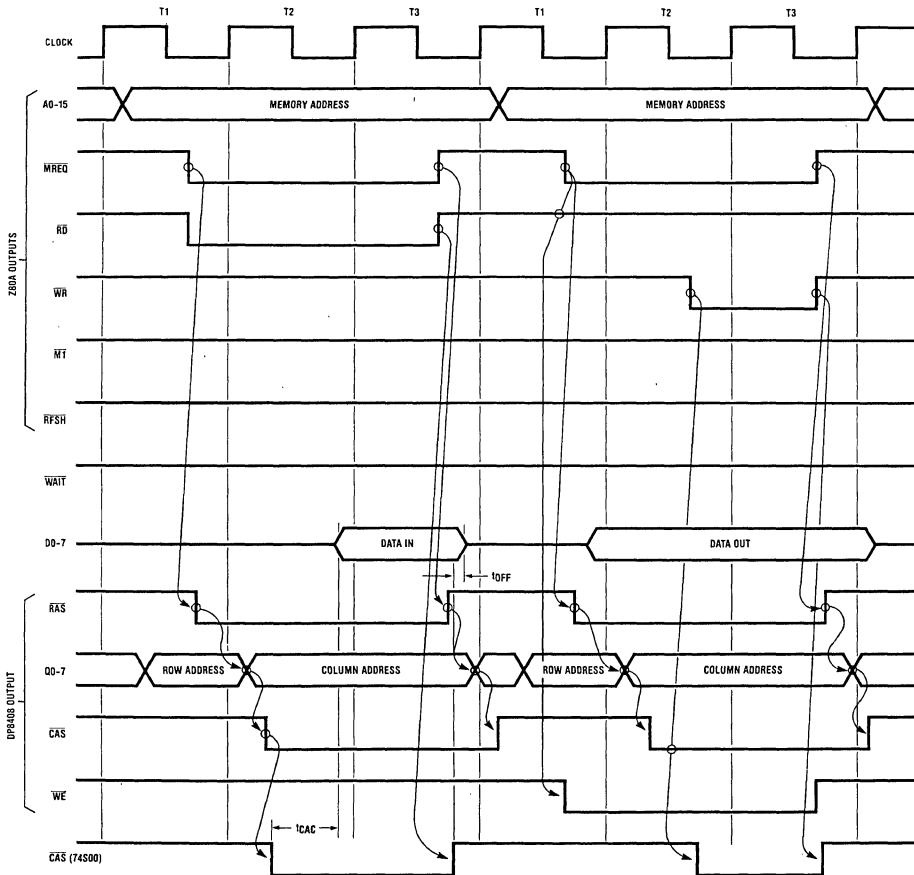


Figure 7. Z80A Memory Read and Memory Write Cycle

The following formulas allow designers to select the appropriate dynamic memory, based on different CPU and DP8408 speed versions, to allow the CPU full speed of operation:

$$\begin{aligned} \text{max. } t_{\text{CAC}}: & 1.5 \times t_{\text{Cmin}} - t_{\text{DL}\phi}(\text{MR}) - t_{\text{R1CL}} - \\ & t_{\text{CASDLY}} - t_{\text{S}\phi}(\text{D}) \\ \text{min. } t_{\text{RP}}: & tw(\phi\text{H}) = tw(\phi\text{H}) + t_f - 20 \\ \text{min. } t_{\text{RAS}}: & tw(\text{MRL}) - 20 = t_{\text{C}} - 50 \end{aligned}$$

Dynamic RAM Parameters:

$$\begin{aligned} t_{\text{CAC}}: & \text{access time from } \overline{\text{CAS}} \\ t_{\text{RP}}: & \text{RAS precharge time} \\ t_{\text{RAS}}: & \text{RAS pulse width} \end{aligned}$$

Z80 Parameters:

$$\begin{aligned} t_{\text{C}}: & \text{clock period} \\ tw(\phi\text{H}): & \text{clock pulse width, clock high} \\ t_f: & \text{clock fall time} \\ t_{\text{DL}\phi}(\text{MR}): & \overline{\text{MREQ}} \text{ delay from falling edge of clock,} \\ & \text{MREQ low} \\ t_{\text{S}\phi}(\text{D}): & \text{Data set up time to rising edge of} \\ & \text{clock during M1 cycle} \end{aligned}$$

DP8408 and 74S00 Parameters:

$$\begin{aligned} t_{\text{R1CL}}: & \overline{\text{RASIN}} \text{ to } \overline{\text{CAS}} \text{ output delay} \\ t_{\text{CASDLY}}: & \text{propagation delay of the two 74S00} \\ & \text{NAND gates} \end{aligned}$$

For example, if the Z80A (4MHz) and the DP8408 are used, then:

$$\begin{aligned} \text{max. } t_{\text{CAC}}: & 1.5(250) - 85 - 132 - 13 - 50 = 95 \text{ ns} \\ \text{min. } t_{\text{RP}}: & 110 + 20 - 20 = 110 \text{ ns} \\ \text{min. } t_{\text{RAS}}: & t_{\text{C}} - 50 = 200 \text{ ns} \\ t_{\text{R1CL}} \text{ max.} & \\ \text{(mode 6):} & 132 \text{ ns at } 15 \text{ pF load} \\ t_{\text{CASDLY}} \text{ max.}: & 13 \text{ ns at } 50 \text{ pF load} \end{aligned}$$

Therefore, in this case, the designer should choose a dynamic memory which has maximum t_{CAC} of 95ns, minimum t_{RP} of 110ns and minimum t_{RAS} of 200ns.

DP8409 and MC68B09E Interface

DP8409 Overview:

The DP8409 Dynamic RAM Controller/Driver is designed to control all multiplexed-address dynamic RAMs. It consists of two 9-bit address latches and a 9-bit refresh counter, thus allowing control of all 16k, 64k, and the coming generation 256k dynamic RAMs. More important, all the DP8409 outputs are capable of driving 500pF loads.

The DP8409 basically has eight modes of operation: Externally Controlled Refresh, Automatic Forced Refresh, Internal Auto Burst Refresh, All RAS Auto Write, Externally Controlled Access, Auto Access (slow t_{RAH} and with hidden refresh), Fast Auto Access (fast t_{RAH}) and Set End of Count. Of all these modes, Auto Access (mode 5) and Auto Forced Refresh (mode 1) are the most popular and will be used throughout this application. Mode 5 requires only $\overline{\text{RASIN}}$ to initiate a memory access cycle, because all the dynamic RAM's

control signals are automatically delayed from this input, as shown in *Figure 1*. To attain maximum system throughput, it is obviously advantageous to perform refreshes without interrupting the system. The DP8409 can do this by monitoring the $\overline{\text{CS}}$ input to see if it is high. If $\overline{\text{CS}}$ is high, the RAMs are not being accessed. If $\overline{\text{CS}}$ is high for one cycle, the DP8409 performs a hidden refresh during this cycle, and stops in time for the system to start another access. But if a hidden refresh does not occur in a specific time slot, a refresh must be forced and this can be done by using Mode 1, Automatic Forced Refresh.

To perform automatic forced refresh, the DP8409 must receive two clock signals: the refresh period clock, RFCK, and RGCK, the RAS-generator clock; RGCK can be the microprocessor clock. It takes approximately four RGCK clock periods to perform this automatic forced refresh. The DP8409 gives preference to hidden refresh using RFCK as a level reference. The refresh time slot commences as RFCK goes high. If $\overline{\text{CS}}$ goes high while RFCK is high, the refresh counter is enabled in the address outputs. All four RAS outputs follow $\overline{\text{RASIN}}$; so to perform a hidden refresh, $\overline{\text{RASIN}}$ must be set low and the refresh counter gets incremented as $\overline{\text{RASIN}}$ goes high. The DP8409 allows only one such hidden refresh to occur with a clock cycle of RFCK to minimize power consumption.

If a hidden refresh does not occur the DP8409 must force a refresh before RFCK begins a new cycle on a low-to-high transition. Therefore, as RFCK goes low (and a hidden refresh has not occurred), RF I/O (Refresh Request) goes low, requesting that a refresh be performed. When the system acknowledges the request, it sets M2 low, and prevents further access to the DP8409. Then two RGCK negative edges after M2 has gone low, all four RAS outputs go low and remain low for two RGCK clock periods. After all four RAS outputs have gone low, M2 can go high any time to end the Automatic Forced Refresh. The DP8409 allows only one automatic refresh to occur within a clock cycle of RFCK.

Memory Access:

The MC68B09E starts a memory access cycle when E goes low, then the memory address becomes valid on the Address Bus A0-15. This address is decoded to provide Chip Select ($\overline{\text{CS}}$) to the DP8409. Then Q goes high and sets $\overline{\text{RASIN}}$ low from the PAL[®] Control Logic as shown in *Figure 12*. Note that $\overline{\text{CS}}$ must go low for a minimum of 10ns before the assertion of $\overline{\text{RASIN}}$ for a proper memory access. This is important because a false hidden refresh may take place when this 10ns minimum setup time is not met. $\overline{\text{RASIN}}$ goes low initiating the auto access sequence as shown in *Figure 1*. Mode 5 guarantees a 30ns minimum for row address hold time and a minimum of 8ns column address set up time. $\overline{\text{RASIN}}$ remains low until E goes low at the end of the current access cycle. Using the 16R6 A-1 Programmable Array Logic (25ns PAL), the maximum access time from $\overline{\text{CAS}}$ of the selected dynamic RAM is determined as follows:

$$\begin{aligned} \text{Max. } t_{\text{CAC}}: & 3 \times 125 - 25 - 160 - 40 = 150 \text{ ns} \quad 8409 \\ t_{\text{CAC}}: & 3 \times 125 - 25 - 130 - 40 = 180 \text{ ns} \quad 8409-2 \\ \text{Q high to} & \\ \text{E low:} & 3 \times 125 \text{ ns (8 MHz clock)} = 375 \text{ ns} \end{aligned}$$

Q high to $\overline{\text{RASIN}}$ low: 25 ns (16R6 A-1 PAL Parameter)
 $\overline{\text{RASIN}}$ to CAS
 Output low: 160 ns (DP8409's t_{R1CL} , Mode 5, at 500 pF load)
 130 ns (DP8409-2's t_{R1CL})
 Read data setup time (before E going low): 40 ns

Memory Refresh:

As described above, $\overline{\text{RASIN}}$ goes active when Q and/or E are high. This scheme, therefore, maximizes chances for hidden refresh because $\overline{\text{CS}}$ is high during nondynamic memory cycle. For example, when the CPU is executing internal operation or the CPU is accessing ROM or I/O, $\overline{\text{CS}}$ is high during these times. The DP8409 therefore performs a hidden refresh as $\overline{\text{RASIN}}$ goes low, assuming that RFCK is high.

However, if no hidden refresh occurs while RFCK was high, RF I/O goes low immediately after the RFCK high-to-low transition requests a forced refresh. The PAL Control Logic samples RF I/O, when E and Q are high and low respectively, to set M2 (RFSH) low, as shown in Figure 13. Once M2 has gone low, a forced refresh automatically occurs (as described in the DP8409 Overview). M2 remains low for four system clock periods to allow for this forced refresh. If the current microprocessor cycle is a non-dynamic memory cycle ($\overline{\text{CS}}$ is high), this refresh is transparent to the microprocessor and $\overline{\text{STRETCH}}$ remains high (E and Q are not stretched). Nevertheless, if the current cycle is a dynamic memory access cycle, $\overline{\text{STRETCH}}$ goes low stretching E and Q for a maximum of four system clocks. $\overline{\text{RASIN}}$ for the pending access will be issued a full system clock after M2 has gone high; this is to allow some RAS precharge time for the dynamic RAM. After this, memory will be accessed in the manner as described in the Memory Access Cycle.

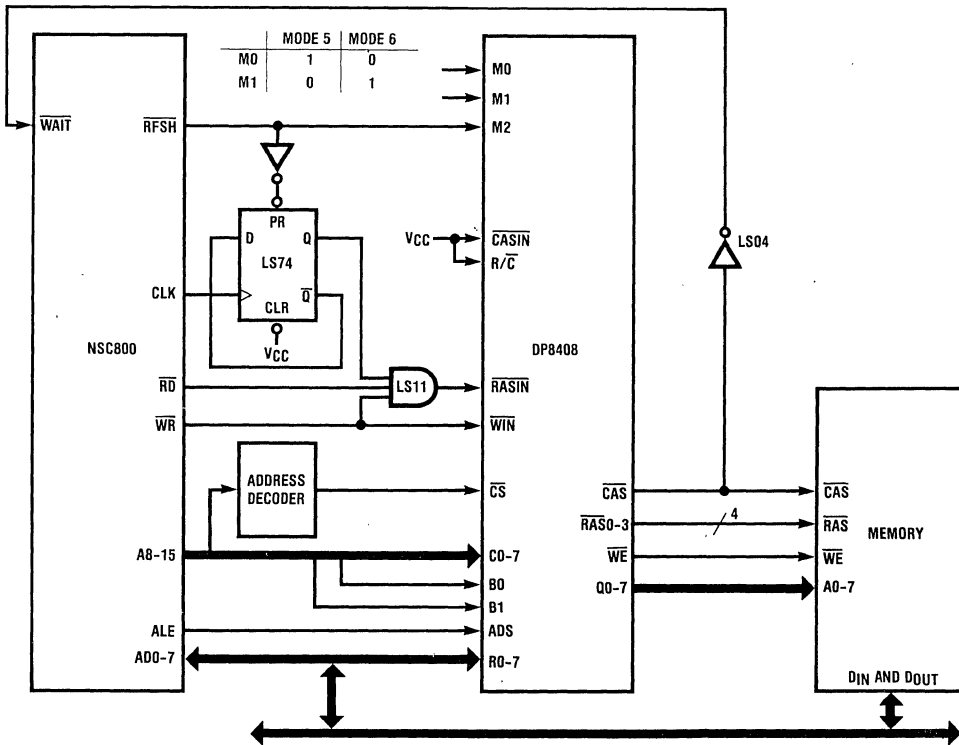


Figure 8. NSC800 and DP8408 Interface

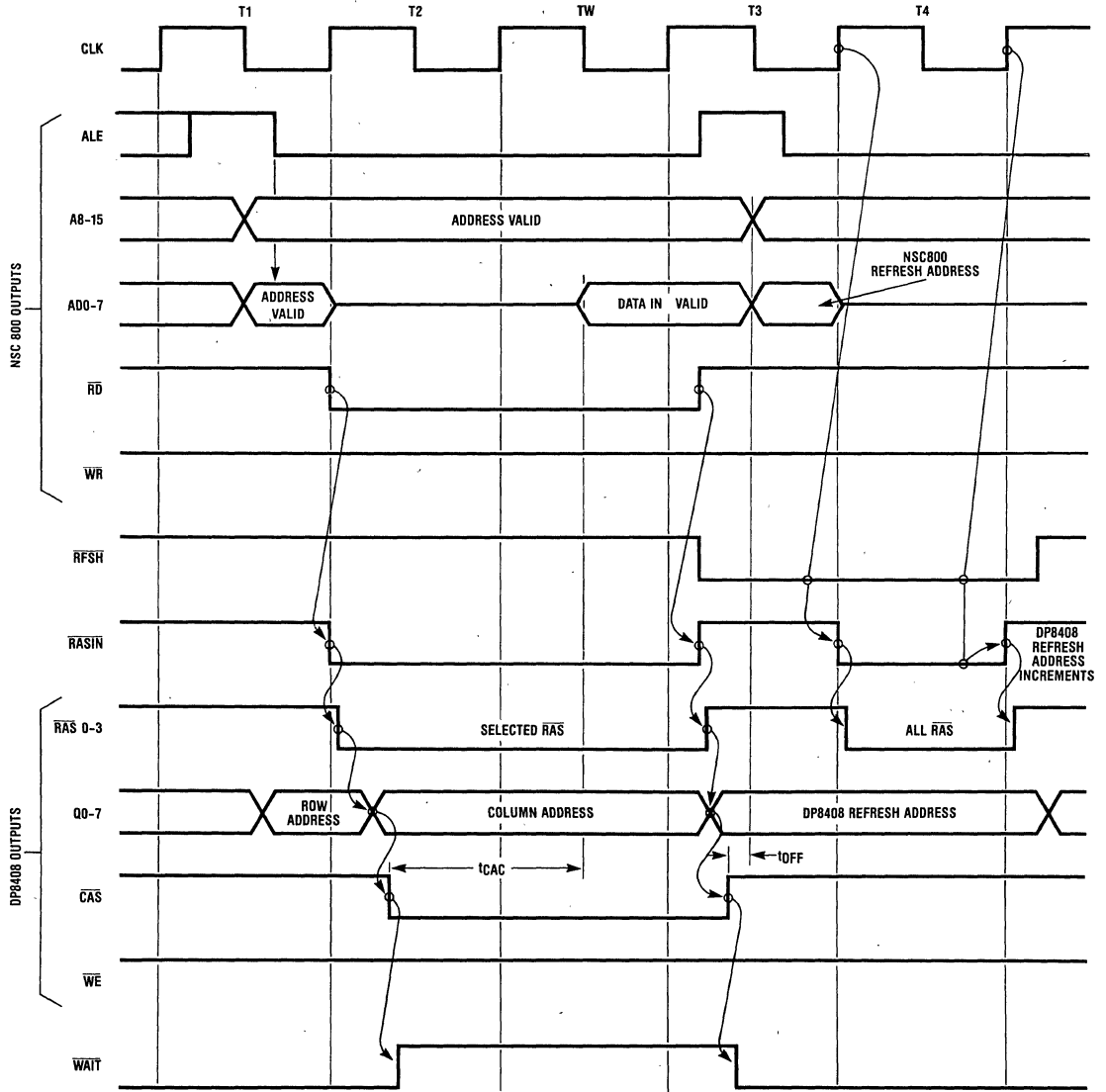


Figure 9. NSC800 Op Code Fetch Cycle Showing Memory Refresh

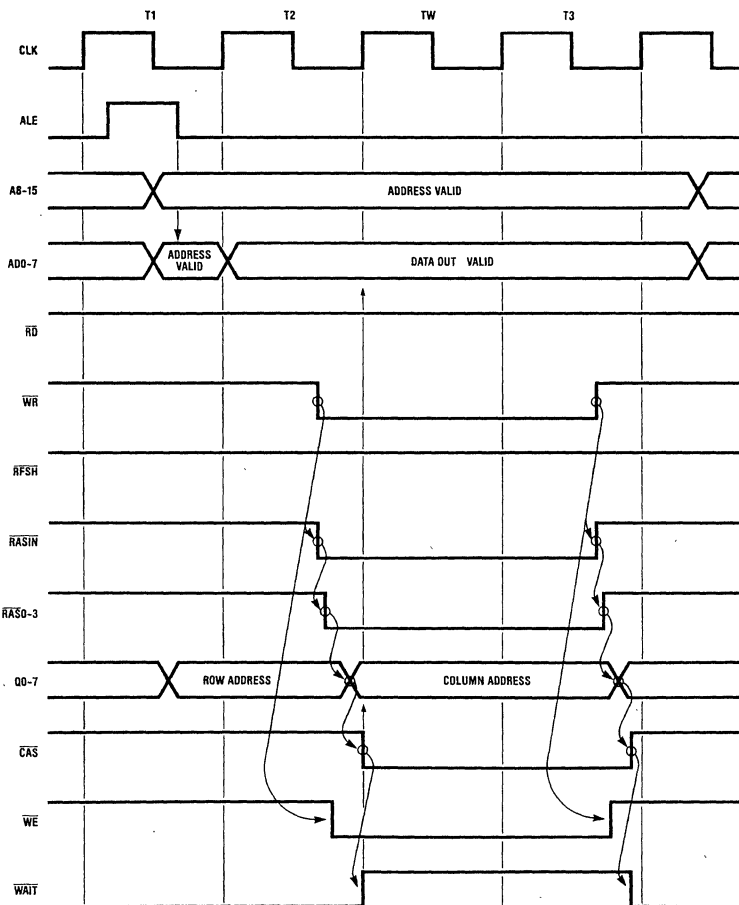


Figure 10. NSC800 Memory Write Cycle

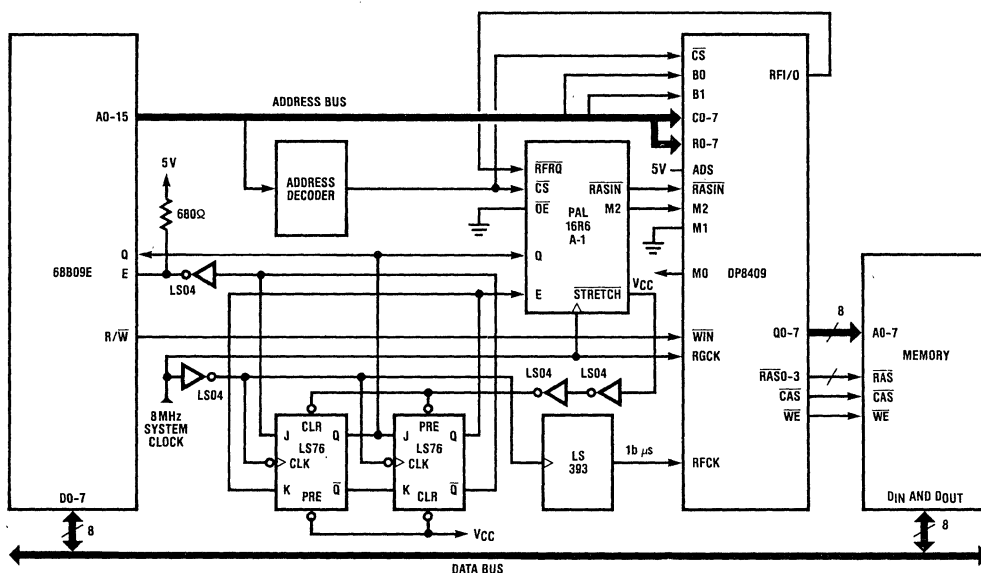
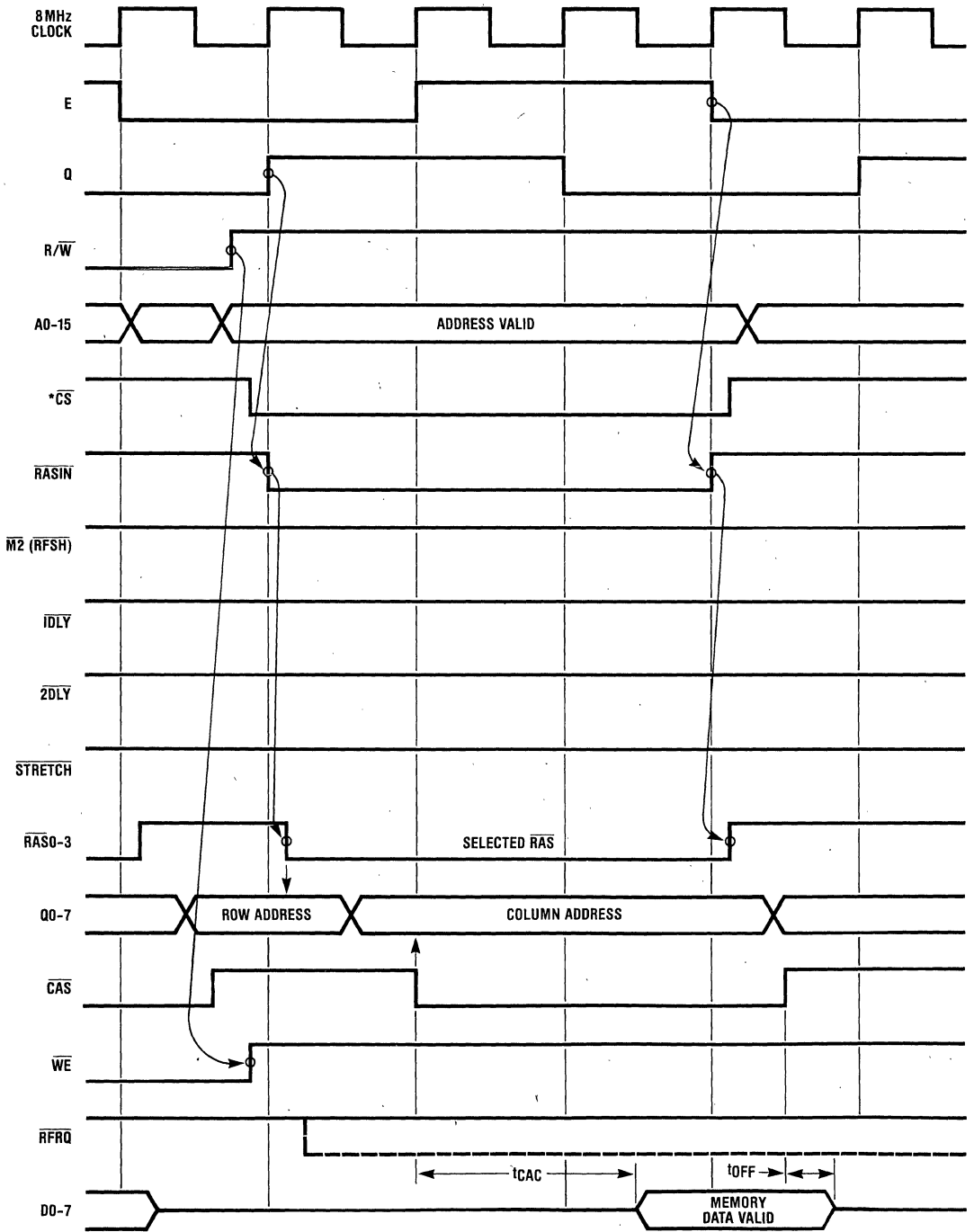


Figure 11. MC68B09E and DP8409 Interface



*IF CS IS HIGH THROUGHOUT THIS CYCLE (RFSH IS ALSO HIGH), HIDDEN REFRESH OCCURS INSTEAD OF A MEMORY ACCESS.

Figure 12. MC68B09E Memory Read Cycle

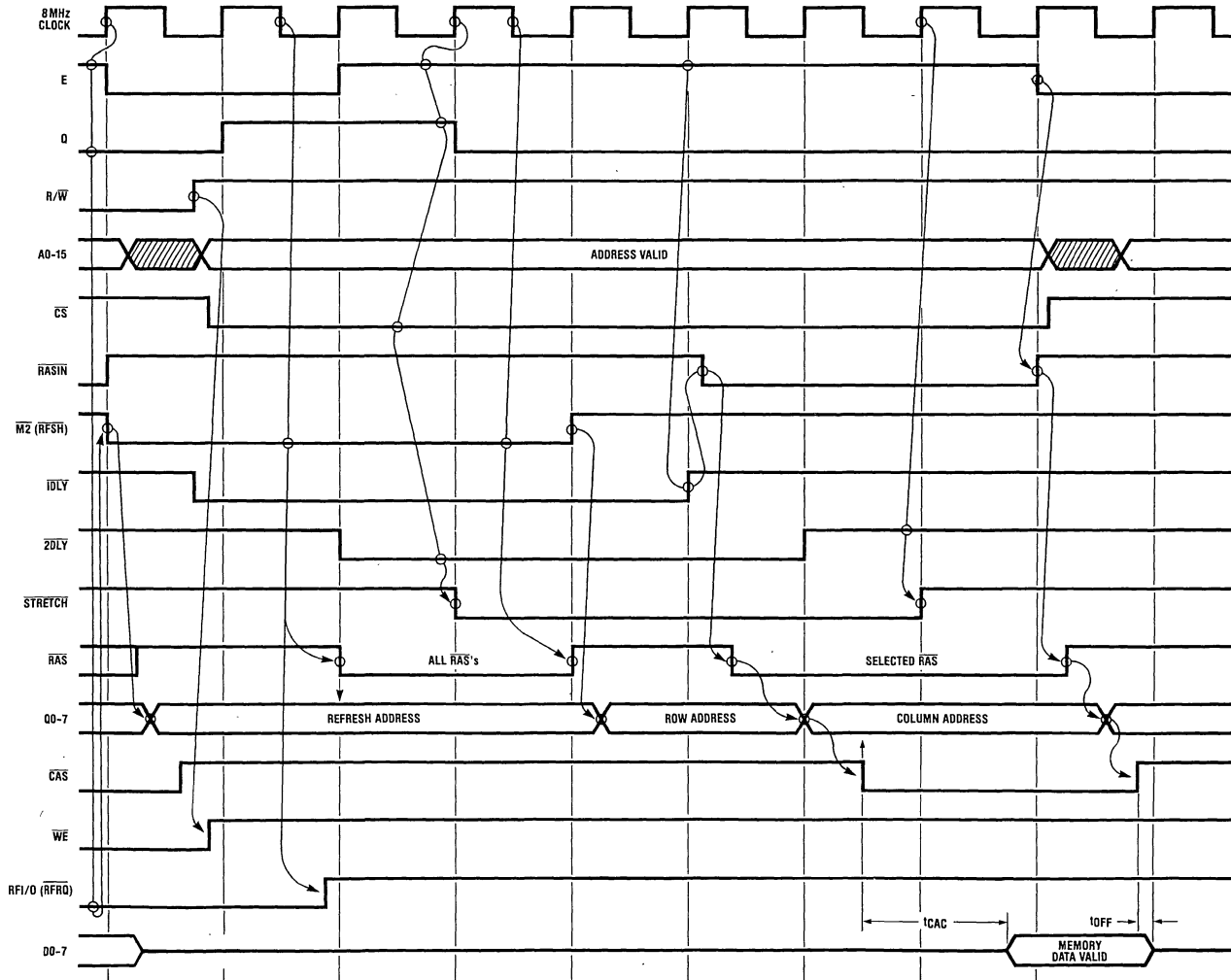


Figure 13. MC68B09E Forced Refresh and Memory Read Cycle

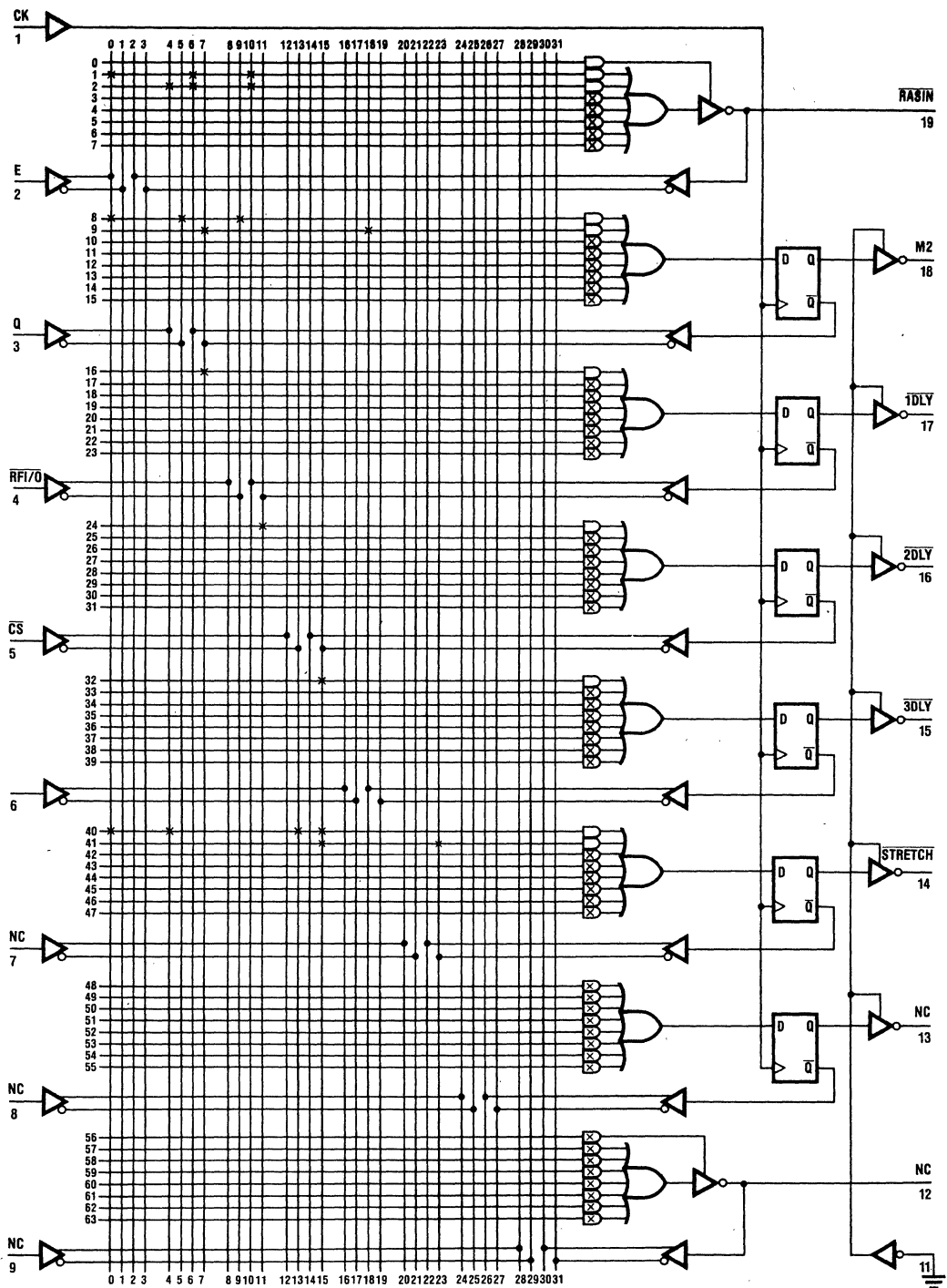


Figure 14. PAL (16R6 A-1) Control Logic

Memory Systems with ECC Using the DP8400

National Semiconductor
Application Brief #2
Brian Edem
June 1982



This brief explains how a memory system can easily perform single error correction, double error detection, auto accessing and refreshing of memory, and byte writing.

Figure 1 shows the NS16032 with DP8409, DP8400, and a 2-PAL® (Programmable Array Logic) controller. The memory cycle for the NS16032 starts at the CPU clock cycle where the address strobe goes active. At the middle of this clock cycle, the 74ALS02 latch is set, providing RASIN to the DP8409 Dynamic RAM Controller, which starts its Auto Access cycle. The latch output is also sent to the two PAL controllers, indicating that a memory cycle has started. On the next PAL clock cycle (50 ns later), the PAL will enter one of five memory cycles: Read, Byte-Write, Word-Write, or Cycle Inhibit.

For a read cycle, one wait state will be needed, so the controller pulls the NCWAIT line low for one CPU clock cycle. Three CPU clock cycles after RASIN, the corrected data is latched at the output of the DP8400, the memory buffers are disabled, and the DP8400's output buffers are enabled. At the beginning of the fifth CPU clock cycle, the CPU latches the data from the data bus, and the PAL deactivates all control signals, resets the 74ALS02 latch, and outputs an interrupt to the CPU if a double error is detected. This allows the CPU to gracefully crash or perform a memory test on the system.

In a byte-write cycle, the data must first be read from memory to be corrected if necessary. The new byte to be written, along with the byte that remains unchanged, will then be written to memory with the new checkbits.

The byte-write memory cycle needs two wait states, so the PAL controller first pulls the NCWAIT line low for two CPU clock cycles. Three CPU clock cycles after RASIN is activated, corrected data is latched at the output of the DP8400. Also at this time the memory buffers are disabled, the new byte from the CPU and the unaddressed memory byte from the DP8400 are enabled onto the internal data bus, creating a new word of data. A half of the CPU clock cycle after the new data is enabled, it is latched into the DP8400, the mode of which has been changed to generate check bits. A half of the CPU clock cycle after the data has been latched into the input of the DP8400, the data is again latched at the output to the DP8400 along with the newly generated check bits. Also at this time, a write strobe is generated by the PAL. At the end of the write strobe, the PAL outputs a reset pulse, resetting the 74ALS02 latch. If a double bit error occurred during the read portion of the memory cycle, then the interrupt will be triggered.

For a word-write cycle, no wait states are used. The buffer from the CPU is enabled, the DP8400 is put into a write mode, and the DP8409 is instructed to write memory. After CAS has occurred, the PAL controller resets the 74ALS02 latch.

During any memory cycle that the dynamic RAM is not selected, the controller effectively performs a cycle inhibit, allowing the DP8409 to perform a refresh if needed. One CPU clock cycle after the cycle starts, the 74ALS02 latch is cleared. The DP8409 will use this short RASIN strobe to generate an All-RAS strobe if a hidden refresh is pending.

If a hidden refresh has not occurred in the allocated time (period of RFCK high), a forced refresh will be requested. The PAL controller will wait for the end of the current memory cycle, and immediately request a cycle hold, and then switch the DP8409 to the auto refresh mode. While the NS16201 is in the cycle hold state, NTSSO will stay high, preventing the start of another memory cycle. After sufficient time has been allowed for the DP8409 to perform a forced refresh, the PAL controller will remove the cycle hold.

Figure 2 shows how, using the 68000, DP8409 and DP8400, and a controller, the same functions can be performed with a memory system controlled by a 68000 micro-processor. Timing for the 68000 system is similar to that for the NS16000, except for forced refresh and the generation of RASIN. The 68000 does not have a feature equivalent to cycle hold, so DTACK (Data Acknowledge) must be delayed if a memory cycle is requested during a forced refresh.

PAL is a registered trademark of Monolithic Memories, Inc.

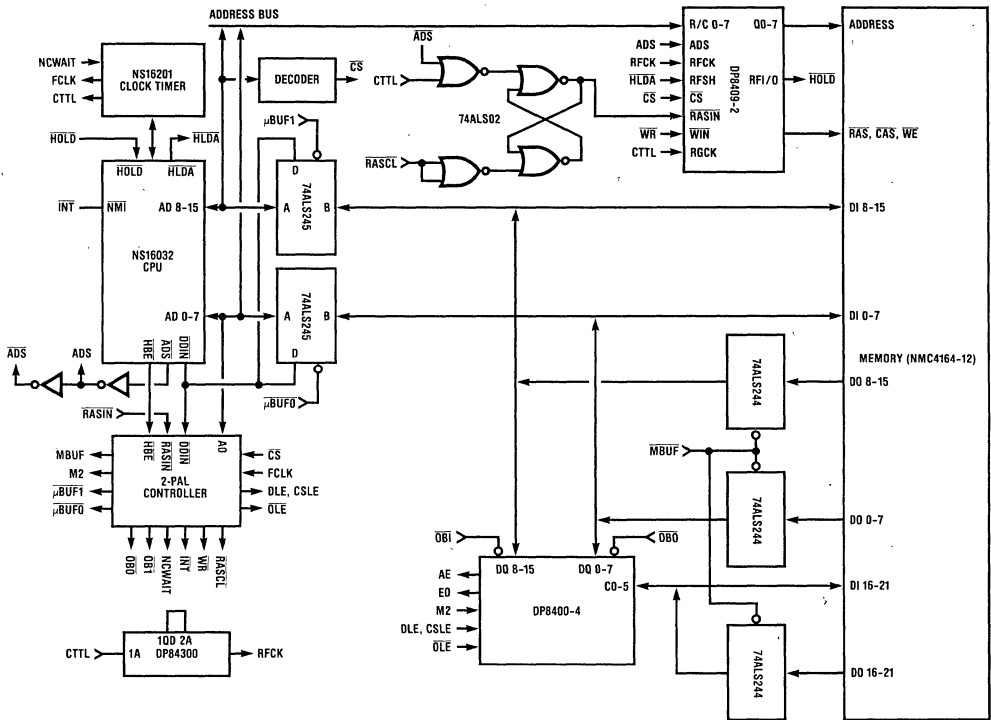


Figure 1. Memory System for NS16032 Using DP8409, DP8400, and 64k Dynamic RAMs, Performing Error Checking/Correcting, Refreshing and Byte-Writing

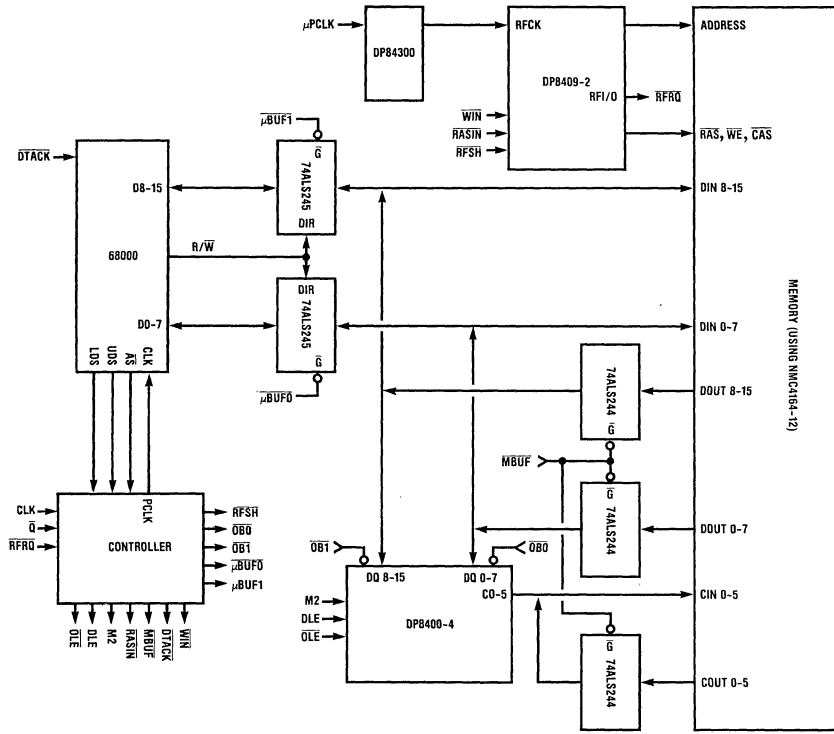


Figure 2. Memory System for the 68000 Using DP8409, DP8400 and 64k Dynamic RAMs



Section 8 Microprocessor Support



TEMPERATURE RANGE		DESCRIPTION	PAGE NUMBER
- 55 °C to + 125 °C	0 °C to + 70 °C		
DP8212M	DP8212	8-Bit Input/Output Port	8-4
*DP8216M	DP8216	4-Bit Bidirectional Bus Transceiver	8-11
*DP8226M	DP8226	4-Bit Bidirectional Bus Transceiver	8-11
—	DP8224	Clock Generator and Driver	8-16
*DP8228M	DP8228	System Controller and Bus Driver	8-22
*DP8238M	DP8238	System Controller and Bus Driver	8-22
—	NS16201	NS16000 Timing Control Unit	Microprocessor

*Also available screened in accordance with MIL-STD-883 Class B. Refer to National Semiconductor's "The Reliability Handbook".

MICROPROCESSOR SUPPORT CIRCUITS

DESCRIPTION	GENERAL PURPOSE	8080 CPU	PART NUMBER		PAGE NO.
			0°C to +70°C	-55°C to +125°C	
8-Bit I/O Port	•	•	DP8212	DP8212M	8-4
4-Bit Parallel Receiver/Driver	•	•	DP8216,	DP8216M,	8-11
			DP8226	DP8226M	8-11
Clock Generator/Driver		•	DP8224		8-16
System Controller/Bus Driver		•	DP8228,	DP8228M,	8-22
			DP8238	DP8238M	8-22
8-Bit 48 mA Bus Transceiver	•		DP8303	DP7303	2-6
8-Bit 48 mA Bus Transceiver	•		DP8304B	DP7304B	2-11
8-Bit 48 mA Bus Transceiver	•		DP8307	DP7307	2-16
8-Bit 48 mA Bus Transceiver	•		DP8308	DP7308	2-20
CRT Controller	•	•	DP8350		5-6
CRT Controller	•	•	DP8352,		5-6
CRT Controller	•	•	DP8353		5-6
Octal D-Type Latch	•		MM74C373	MM54C373	CMOS
Octal D-Type Flip-Flop	•		MM74C374	MM54C374	CMOS
16-Key Encoder	•		MM74C922	MM54C922	CMOS
20-Key Encoder	•		MM54C923	MM54C923	CMOS
Octal Transparent D Latch	•		DM74LS373	DM54LS373	LOGIC
Octal Edge-Triggered D Flip-Flop	•		DM74LS374	DM54LS374	LOGIC

DP8212/DP8212M 8-Bit Input/Output Port

General Description

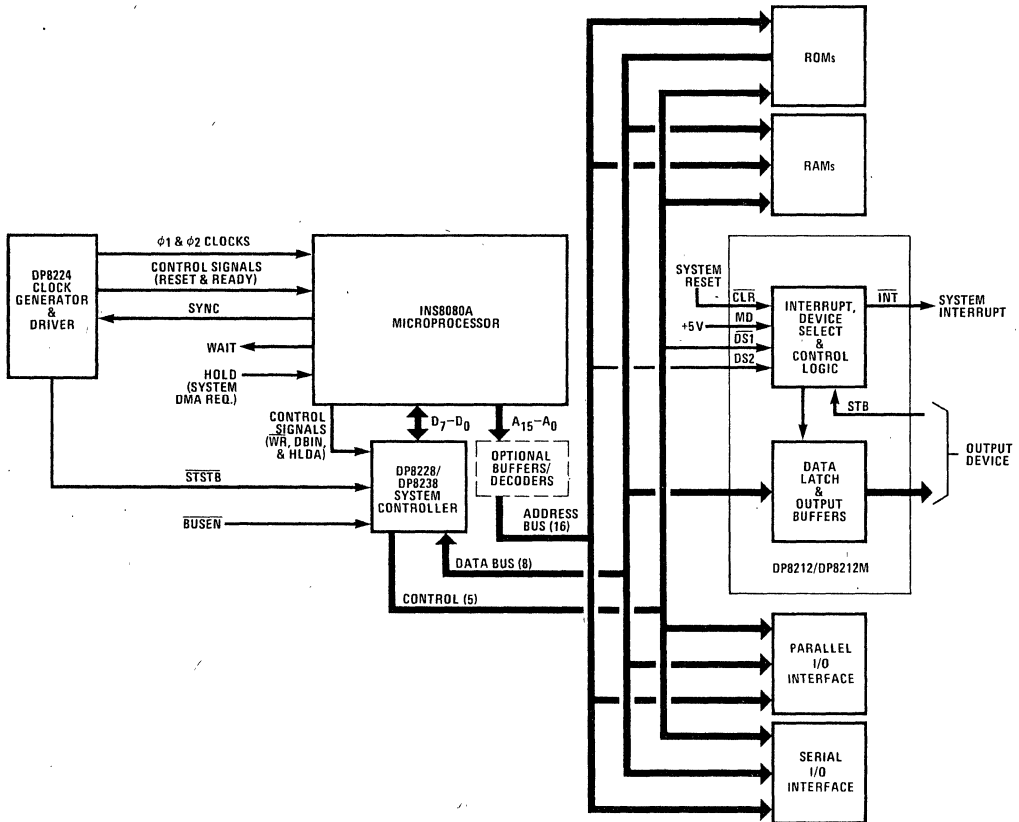
The DP8212/DP8212M is an 8-bit input/output port contained in a standard 24-pin dual-in-line package. The device, which is fabricated using Schottky Bipolar technology, is part of National Semiconductor's N8080A microcomputer family. The DP8212/DP8212M can be used to implement latches, gated buffers, or multiplexers. Thus, all of the major peripheral and input/output functions of a microcomputer system can be implemented with this device.

The DP8212/DP8212M includes an 8-bit latch with TRI-STATE® output buffers, and device selection and control logic. Also included is a service request flip-flop for the generation and control of interrupts to the microprocessor.

Features

- 8-Bit Data Latch and Buffer
- Service Request Flip-flop for Generation and Control of Interrupts
- 0.25mA Input Load Current
- TRI-STATE TTL Output Drive Capability
- Outputs Sink 15mA
- Asynchronous Latch Clear
- 3.65V Output for Direct Interface to INS8080A
- Reduces System Package Count by Replacing Buffers, Latches, and Multiplexers in Microcomputer Systems

N8080A Microcomputer Family Block Diagram



Absolute Maximum Ratings

Storage Temperature	-65°C to +160°C
All Output or Supply Voltages	-0.5V to +7V
All Input Voltages	-1.0V to 5.5V
Output Currents	125 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	1903 mW
Molded Package	2005 mW

*Derate cavity package 12.7 mW/°C above 25°C; derate molded package 16.0 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DP8212M	4.50	5.50	V _{DC}
DP8212	4.75	5.25	V _{DC}
Operating Temperature (T _A)			
DP8212M	-55	+125	°C
DP8212	0	+75	°C

Note: Maximum ratings indicate limits beyond which permanent damage may occur. Continuous operation at these limits is not intended and should be limited to those conditions specified under dc electrical characteristics.

Electrical Characteristics (Min ≤ T_A ≤ Max, Min ≤ V_{CC} ≤ Max, unless otherwise noted)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
I _F	Input Load Current, STB, DS2, $\overline{\text{CLR}}$, DI ₁ -DI ₈ Inputs	V _F = 0.45V			-0.25	mA
I _F	Input Load Current, MD Input	V _F = 0.45V			-0.75	mA
I _F	Input Load Current, $\overline{\text{DS1}}$ Input	V _F = 0.45V			-1.0	mA
I _R	Input Leakage Current, STB, DS2, $\overline{\text{CLR}}$, DI ₁ -DI ₈ Inputs	V _R = V _{CC} Max			10	μA
I _R	Input Leakage Current, MD Input	V _R = V _{CC} Max			30	μA
I _R	Input Leakage Current, $\overline{\text{DS1}}$ Input	V _R = V _{CC} Max			40	μA
V _C	Input Forward Voltage Clamp	I _C = -5 mA			-1	V
V _{IL}	Input "Low" Voltage	DP8212M			0.80	V
		DP8212			0.85	V
V _{IH}	Input "High" Voltage		2.0			V
V _{OL}	Output "Low" Voltage	I _{OL} = 10 mA, DP8212M			0.45	V
		I _{OL} = 15 mA, DP8212			0.45	V
V _{OH}	Output "High" Voltage	I _{OH} = -0.5 mA, DP8212M	3.40	4.0		V
		I _{OH} = -1.0 mA, DP8212	3.65	4.0		V
I _{SC}	Short-Circuit Output Current	V _O = 0V, V _{CC} = 5V	-15		-75	mA
I _{lO}	Output Leakage Current, High Impedance State	V _O = 0.45V/V _{CC} Max			20	μA
I _{CC}	Power Supply Current	DP8212M		90	145	mA
		DP8212		90	130	mA

Capacitance *

F = 1MHz, V_{BIAS} = 2.5V, V_{CC} = 5V, T_A = 25°C.

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS
C _{IN}	DS1, MD Input Capacitance		9	12	pF
C _{IN}	DS2, $\overline{\text{CLR}}$, STB, DI ₁ -DI ₈ Input Capacitance		5	9	pF
C _{OUT}	DO1-DO8 Output Capacitance		8	12	pF

*This parameter is sampled and not 100% tested.

Switching Characteristics

(Min $\leq T_A \leq$ Max, Min $\leq V_{CC} \leq$ Max)

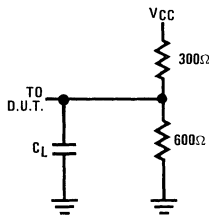
SYMBOL	PARAMETER	CONDITIONS	DP8212M		DP8212		UNITS
			MIN	MAX	MIN	MAX	
tPW	Pulse Width		40		30		ns
tPD	Data to Output Delay	(Note 5)		30		30	ns
tWE	Write Enable to Output Delay	(Note 5)		50		40	ns
tSET	Data Set-Up Time		20		15		ns
tH	Data Hold Time		30		20		ns
tR	Reset to Output Delay	(Note 5)		55		40	ns
tS	Set to Output Delay	(Note 5)		35		30	ns
tE	Output Enable/Disable Time	(Note 6)		50		45	ns
tC	Clear to Output Delay	(Note 5)		65		55	ns

Switching Conditions

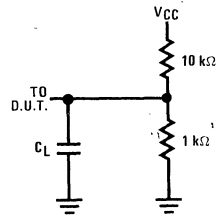
Conditions of Test:

1. Input Pulse Amplitude = 2.5V.
2. Input Rise and Fall Times = 5ns.
3. Between 1V and 2V Measurements made at 1.5V with 15mA & 30pF Test Load.
4. C_L includes jig and probe capacitance.
5. $C_L = 30$ pF.
6. $C_L = 30$ pF except for DP8212M tE(DISABLE) $C_L = 5$ pF

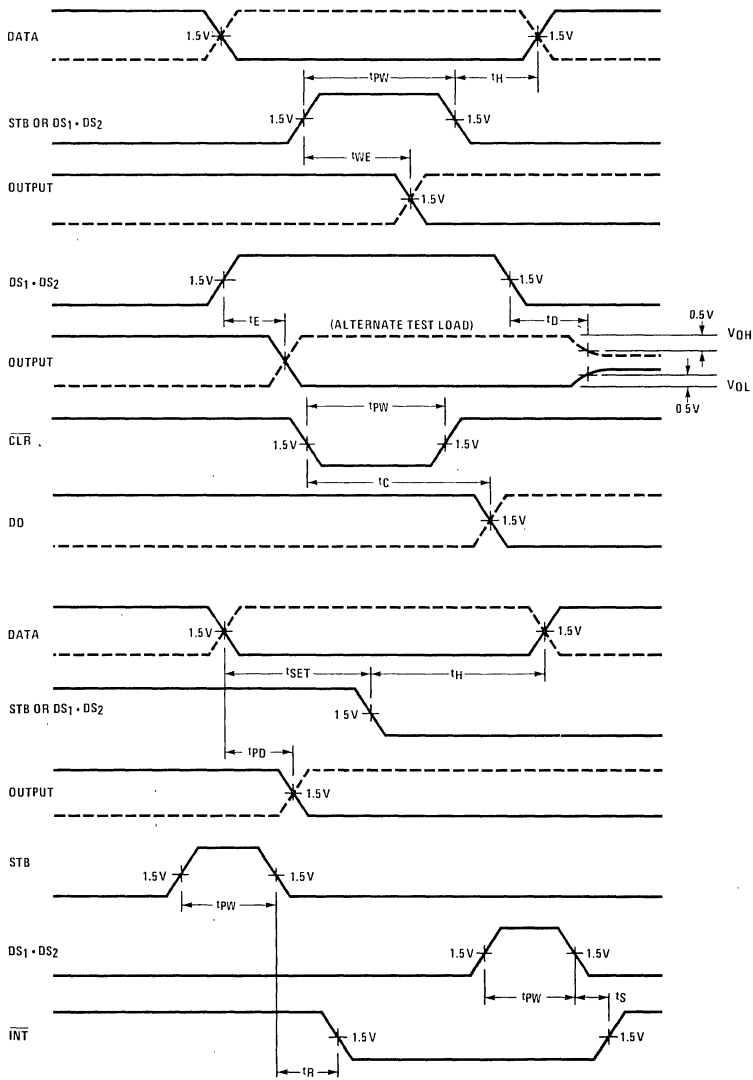
Test Load



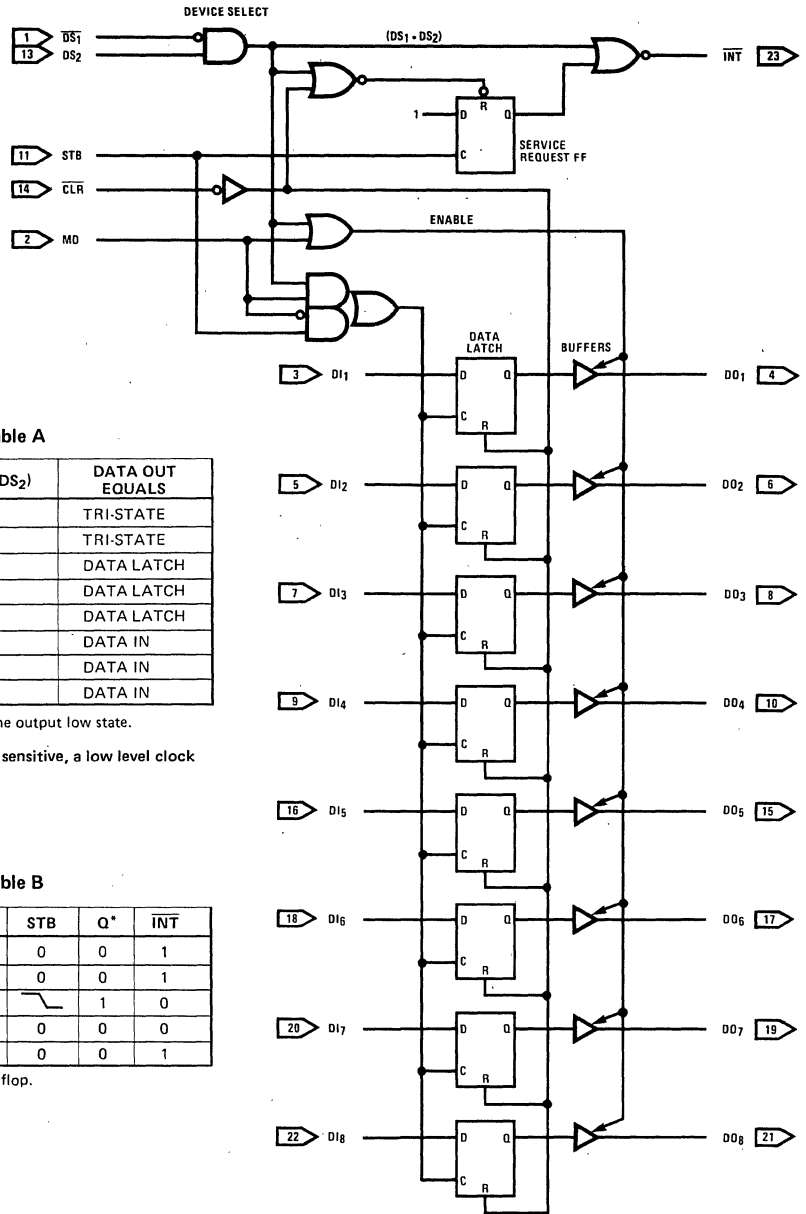
Alternate Test Load
(Refer to Timing Diagram)



Timing Diagram



Logic Diagram



Logic Table A

STB	MD	(DS ₁ -DS ₂)	DATA OUT EQUALS
0	0	0	TRI-STATE
1	0	0	TRI-STATE
0	1	0	DATA LATCH
1	1	0	DATA LATCH
0	0	1	DATA LATCH
1	0	1	DATA IN
0	1	1	DATA IN
1	1	1	DATA IN

CLR $\overline{\text{L}}$ resets data latch to the output low state.

The data latch clock is level sensitive, a low level clock latches the data.

Logic Table B

CLR	(DS ₁ -DS ₂)	STB	Q*	INT
0 RESET	0	0	0	1
1	0	0	0	1
1	0	$\overline{\text{L}}$	1	0
1	1 RESET	0	0	0
1	0	0	0	1

* Internal Service Request flip-flop.

Functional Pin Definitions

The following describes the function of all the DP8212/DP8212M input/output pins. Some of these descriptions reference internal circuits.

INPUT SIGNALS

Device Select ($\overline{\text{DS}}_1$, DS₂): When $\overline{\text{DS}}_1$ is low and DS₂ is high, the device is selected. The output buffers are enabled

and the service request flip-flop is asynchronously reset (cleared) when the device is selected.

Mode (MD): When high (output mode), the output buffers are enabled and the source of the data latch clock input is the device selection logic (DS₁ · DS₂). When low (input mode), the state of the output buffers is determined by the device selection logic (DS₁ · DS₂) and the source of the data latch clock input is the strobe (STB) input.

Functional Pin Definitions (Continued)

Strobe (STB): Used as data latch clock input when the mode (MD) input is low (input mode). Also used to synchronously set the service request flip-flop, which is negative edge triggered.

Data In (DI₁ – DI₈): Eight-bit data input to the data latch, which consists of eight D-type flip-flops. Incorporating a level sensitive clock while the data latch clock input is high, the Q output of each flip-flop follows the data input. When the clock input returns low, the data latch stores the data input. The clock input high overrides the clear (CLR) input data latch reset.

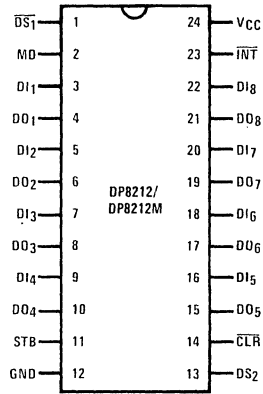
Clear (CLR): When low, asynchronously resets (clears) the data latch and the service request flip-flop. The service request flip-flop is in the non-interrupting state when reset.

OUTPUT SIGNALS

Interrupt (INT): Goes low (interrupting state) when either the service request flip-flop is synchronously set by the strobe (STB) input or the device is selected.

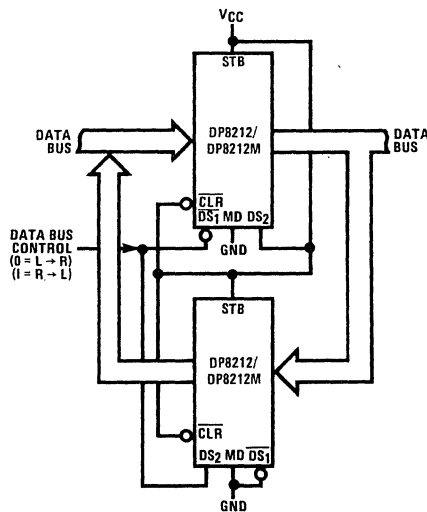
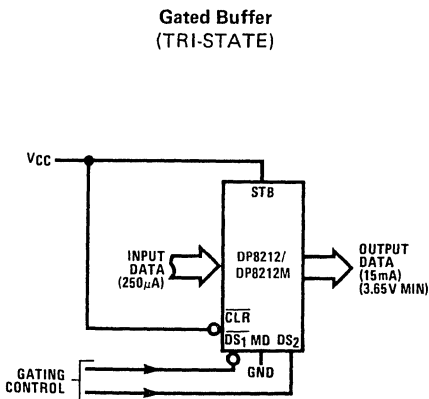
Data Out (DO₁ – DO₈): Eight-bit data output of data buffers, which are TRI-STATE, non-inverting stages. These buffers have a common control line that either enables the buffers to transmit the data from the data latch outputs or disables the buffers by placing them in the high-impedance state.

Connection Diagram



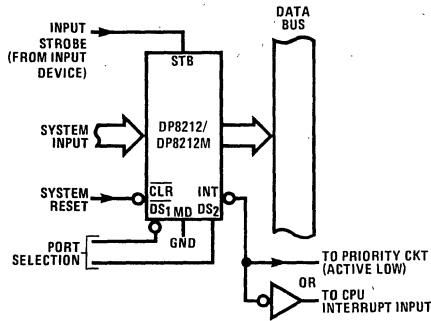
Order Number DP8212J, DP8212N or DP8212MJ
See NS Package J24A or N24A

Applications in Microcomputer Systems

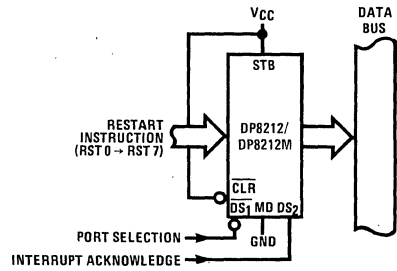


Applications in Microcomputer Systems (Continued)

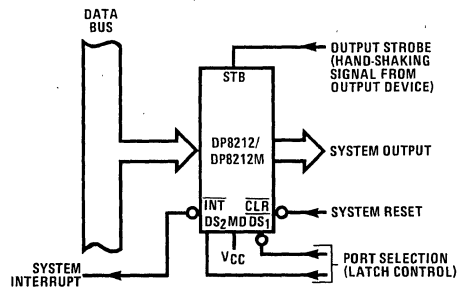
Interrupting Input Port



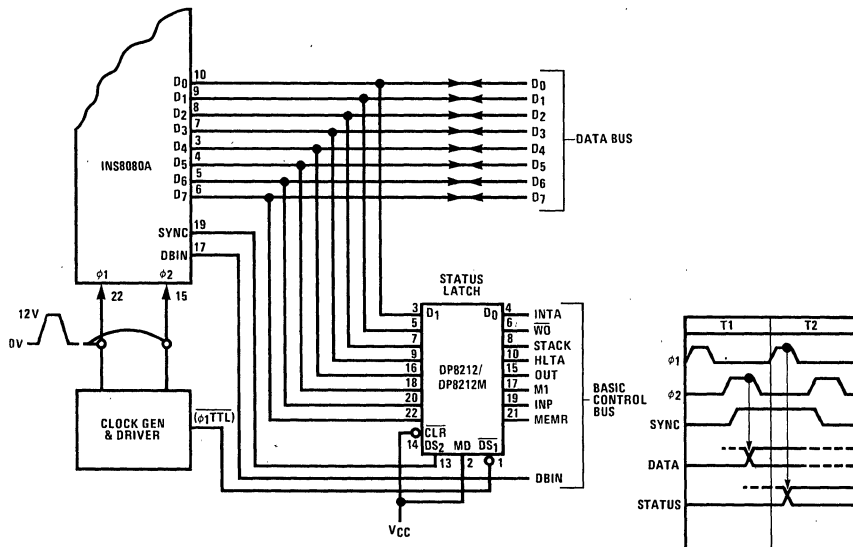
Interrupt Instruction Port



Output Port (with Hand-Shaking)



INS8080A Status Latch



DP8216/DP8216M, DP8226/DP8226M 4-Bit Bidirectional Bus Transceivers

General Description

The DP8216/DP8216M and DP8226/DP8226M are 4-bit bidirectional bus drivers for use in bus oriented applications. The non-inverting DP8216/DP8216M and inverting DP8226/DP8226M drivers are provided for flexibility in system design.

Each buffered line of the four-bit driver consists of two separate buffers that are TRI-STATE® to achieve direct bus interface and bidirectional capability. On one side of the driver the output of one buffer and the input of another are tied together (DB); this side is used to interface to the system side components such as memories, I/O, etc., because its interface is TTL compatible and it has high drive (50 mA). On the other side of the driver the inputs and outputs are separated to provide maximum flexibility. Of course, they can be tied together so that the driver can be used to buffer a true bidirectional bus. The DO outputs on this side of the driver have a special high voltage output drive capability so that direct interface to the 8080 type CPUs is achieved with an adequate amount of noise immunity.

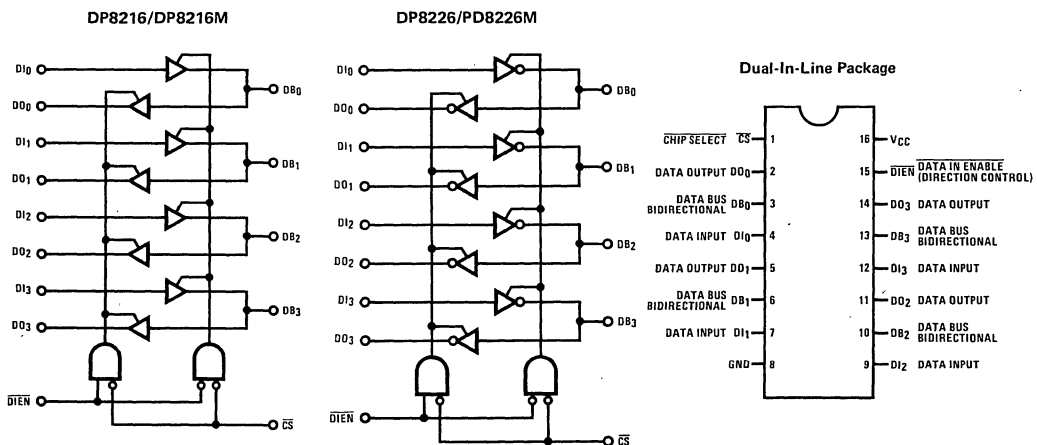
The CS input is a device enable. When it is "high" the output drivers are all forced to their high-impedance state. When it is a "low" the device is enabled and the direction of the data flow is determined by the DIEN input.

The DIEN input controls the direction of data flow, which is accomplished by forcing one of the pair of buffers into its high-impedance state and allowing the other to transmit its data. A simple two-gate circuit is used for this function.

Features

- Data bus buffer driver for 8080 type CPUs
- Low input load current – 0.25 mA maximum
- High output drive capability for driving system data bus – 50 mA at 0.5 V
- Power up-down protection
- DP8216/DP8216M have non-inverting outputs
- DP8226/DP8226M have inverting outputs
- Output high voltage compatible with direct interface to MOS
- TRI-STATE outputs
- Advanced Schottky processing
- Available in military and commercial temperature ranges

Logic and Connection Diagrams



Order Number DP8216J, DP8216N, DP8226J,
DP8226N, DP8216MJ or DP8226MJ
See NS Package J16A or N16A

Absolute Maximum Ratings (Note 1)

	Min	Max	Units
All Output and Supply Voltages	-0.5	+7.0	V
All Input Voltages	-1.0	+5.5	V
Output Currents		125	mA
Storage Temperature	-65	+150	°C
Maximum Power Dissipation* at 25°C			
Cavity Package		1509	mW
Molded Package		1476	mW
Lead Temperature (soldering, 10 seconds)		+300	°C

Operating Conditions

	Min	Max	Units
Supply Voltage, V _{CC}			
DP8216M, DP8226M	4.5	5.5	V
DP8216, DP8226	4.75	5.25	V
Temperature, T _A			
DP8216M, DP8226M	-55	+125	°C
DP8216, DP8226	0	+70	°C

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Electrical Characteristics DP8216, DP8226 V_{CC} = 5 V ± 5% (Notes 2, 3, and 4)

Parameter		Conditions	Limits			Units
Symbol	Description		Min	Typ	Max	
DRIVERS						
V _{IL}	Input Low Voltage				0.95	V
V _{IH}	Input High Voltage		2			V
I _F	Input Load Current	V _F = 0.45 V		-0.03	-0.25	mA
I _R	Input Leakage Current	V _R = 5.25 V			10	μA
V _C	Input Clamp Voltage	I _C = -5 mA			-1.2	V
V _{OL1}	Output Low Voltage	I _{OL} = 25 mA		0.3	0.45	V
V _{OL2}	Output Low Voltage	DP8216 I _{OL} = 55 mA DP8226 I _{OL} = 50 mA		0.5	0.6	V
V _{OH}	Output High Voltage	I _{OH} = -10 mA	2.4	3.0		V
I _{SC}	Output Short Circuit Current	V _{CC} = 5.0 V	-30	-75	-120	mA
I _{lO}	Output Leakage Current TRI-STATE	V _O = 0.45 V/5.5 V			100	μA
RECEIVERS						
V _{IL}	Input Low Voltage				0.95	V
V _{IH}	Input High Voltage		2			V
I _F	Input Load Current	V _F = 0.45 V		-0.08	-0.25	mA
V _C	Input Clamp Voltage	I _C = -5 mA			-1.2	V
V _{OL}	Output Low Voltage	I _{OL} = 15 mA		0.3	0.45	V
V _{OH1}	Output High Voltage	I _{OH} = -1 mA	3.65	4.0		V
I _{SC}	Output Short Circuit Current	V _O ≈ 0 V	-15	-35	-65	mA
I _{lO}	Output Leakage Current TRI-STATE	V _O = 0.45 V/5.5 V			20	μA
CONTROL INPUTS (CS̄, DIEN)						
V _{IL}	Input Low Voltage				0.95	V
V _{IH}	Input High Voltage		2			V
I _F	Input Load Current	V _F = 0.45 V		-0.15	-0.5	mA
I _R	Input Leakage Current	V _R = 5.25 V			20	μA
I _{CC}	Power Supply Current					
	DP8216			95	130	mA
	DP8226			85	120	mA

Electrical Characteristics DP8216M, DP8226M $V_{CC} = 5V \pm 10\%$ (Notes 2, 3 and 4)

DP8216/DP8216M, DP8226/DP8226M


Parameter		Conditions	Limits			Units
Symbol	Description		Min	Typ	Max	
DRIVERS						
V_{IL}	Input Low Voltage DP8216M DP8226M				0.95 0.90	V V
V_{IH}	Input High Voltage		2			V
I_F	Input Load Current	$V_F = 0.45V$		-0.08	-0.25	mA
I_R	Input Leakage Current	$V_R = 5.5V$			40	μA
V_C	Input Clamp Voltage	$I_C = -5mA$			-1.2	V
V_{OL1}	Output Low Voltage	$I_{OL} = 25mA$		0.3	0.45	V
V_{OL2}	Output Low Voltage	$I_{OL} = 45mA$		0.5	0.6	V
V_{OH}	Output High Voltage	$I_{OH} = -5mA$	2.4	3.0		V
I_{SC}	Output Short Circuit Current	$V_{CC} = 5.0V$	-30	-75	-120	mA
$ I_{O} $	Output Leakage Current TRI-STATE	$V_O = 0.45V/5.5V$			100	μA
RECEIVERS						
V_{IL}	Input Low Voltage DP8216M DP8226M				0.95 0.9	V V
V_{IH}	Input High Voltage		2			V
I_F	Input Load Current	$V_F = 0.45V$		-0.08	-0.25	mA
V_C	Input Clamp Voltage	$I_C = -5mA$			-1.2	V
V_{OL}	Output Low Voltage	$I_{OL} = 15mA$		0.3	0.45	V
V_{OH1}	Output High Voltage	$I_{OH} = -0.5mA$	3.4	3.8		V
V_{OH2}	Output High Voltage	$I_{OH} = -2mA$	2.4			V
I_{SC}	Output Short Circuit Current	$V_{CC} = 5.0V$	-15	-35	-65	mA
$ I_{O} $	Output Leakage Current TRI-STATE	$V_O = 0.45V/5.5V$			20	μA
CONTROL INPUTS (CS, DIEN)						
V_{IL}	Input Low Voltage DP8216M DP8226M				0.95 0.9	V V
V_{IH}	Input High Voltage		2			V
I_F	Input Load Current	$V_F = 0.45V$		-0.15	-0.5	mA
I_R	Input Leakage Current	$V_R = 5.5V$			80	μA
I_{CC}	Power Supply Current DP8216M DP8226M			95 85	130 120	mA mA

Switching Characteristics (Notes 2, 3, and 4)

Parameter		Conditions	Limits			Units
Symbol	Description		Min	Typ	Max	
DP8216M, DP8226M, $V_{CC} = 5V \pm 10\%$						
t _{PD1}	Input to Output Delay, DO Outputs	$C_L = 30\text{ pF}$, $R_1 = 300\ \Omega$, $R_2 = 600\ \Omega$		15	25	ns
t _{PD2}	Input to Output Delay, DB Outputs DP8216M DP8226M	$C_L = 300\text{ pF}$, $R_1 = 90\ \Omega$, $R_2 = 180\ \Omega$		19 16	33 25	ns ns
t _E	Output Enable Time DP8216M DP8226M	DO Outputs: $C_L = 30\text{ pF}$, $R_1 = 300\ \Omega/10\text{ k}\Omega$, $R_2 = 600\ \Omega/1\text{ k}\Omega$, DB Outputs: $C_L = 300\text{ pF}$, $R_1 = 90\ \Omega/10\text{ k}\Omega$, $R_2 = 180\ \Omega/1\text{ k}\Omega$		42 36	75 62	ns ns
t _D	Output Disable Time DP8216M DP8226M	DO Outputs: $C_L = 5\text{ pF}$, $R_1 = 300\ \Omega/10\text{ k}\Omega$, $R_2 = 600\ \Omega/1\text{ k}\Omega$, DB Outputs: $C_L = 5\text{ pF}$, $R_1 = 90\ \Omega/10\text{ k}\Omega$, $R_2 = 180\ \Omega/1\text{ k}\Omega$		16 16	40 38	ns ns
DP8216, DP8226 $V_{CC} = 5.0V \pm 5\%$						
t _{PD1}	Input to Output Delay, DO Outputs	$C_L = 30\text{ pF}$, $R_1 = 300\ \Omega$, $R_2 = 600\ \Omega$		15	25	ns
t _{PD2}	Input to Output Delay, DB Outputs DP8216 DP8226	$C_L = 300\text{ pF}$, $R_1 = 90\ \Omega$, $R_2 = 180\ \Omega$		20 16	30 25	ns ns
t _E	Output Enable Time DP8216 DP8226	DO Outputs: $C_L = 30\text{ pF}$, $R_1 = 300\ \Omega/10\text{ k}\Omega$, $R_2 = 600\ \Omega/1\text{ k}\Omega$, DB Outputs: $C_L = 300\text{ pF}$, $R_1 = 90\ \Omega/10\text{ k}\Omega$, $R_2 = 180\ \Omega/1\text{ k}\Omega$		45 35	65 54	ns ns
t _D	Output Disable Time	DO Outputs: $C_L = 5\text{ pF}$, $R_1 = 300\ \Omega/10\text{ k}\Omega$, $R_2 = 600\ \Omega/1\text{ k}\Omega$, DB Outputs: $C_L = 5\text{ pF}$, $R_1 = 90\ \Omega/10\text{ k}\Omega$, $R_2 = 180\ \Omega/1\text{ k}\Omega$		20	35	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the devices should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the -55°C to $+125^\circ\text{C}$ temperature range for the DP8216M and DP8226M and across the 0°C to $+70^\circ\text{C}$ temperature range for the DP8216 and DP8226. All typical values are given for $V_{CC} = 5V$ and $T_A = 25^\circ\text{C}$.

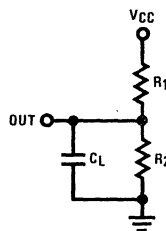
Note 3: All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to ground unless otherwise specified.

Note 4: Only one output at a time should be shorted.

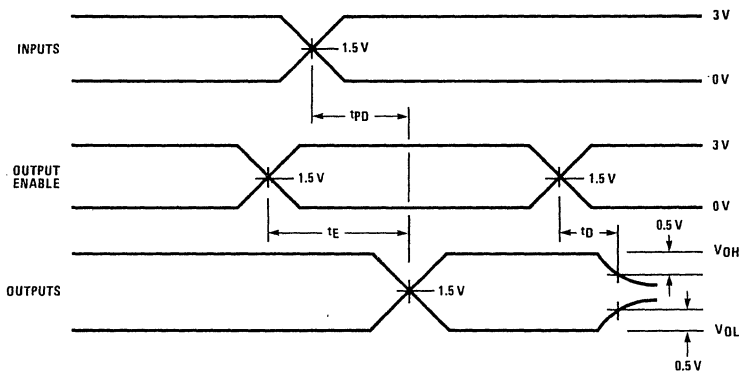
Test Conditions

Input pulse amplitude of 2.5 V.
 Input rise and fall times of 5.0 ns between 1.0 V and 2.0 V.
 Output loading is 5.0 mA and 10 pF.
 Speed measurements are made at 1.5 V levels.

Test Load Circuit



Switching Time Waveforms



Capacitance $T_A = 25^\circ\text{C}$

Symbol	Parameter	Limit			Unit
		Min.	Typ.	Max.	
C _{IN}	Input Capacitance		4	6	pF
C _{OUT}	Output Capacitance				
	DO Outputs		6	10	pF
	DB Outputs		13	18	pF

Note: This parameter is periodically sampled and is not 100% tested. Condition of measurement is $f = 1\text{ MHz}$, $V_{\text{BIAS}} = 2.5\text{ V}$, $V_{\text{CC}} = 5.0\text{ V}$, and $T_A = 25^\circ\text{ C}$.

DP8224 Clock Generator and Driver

General Description

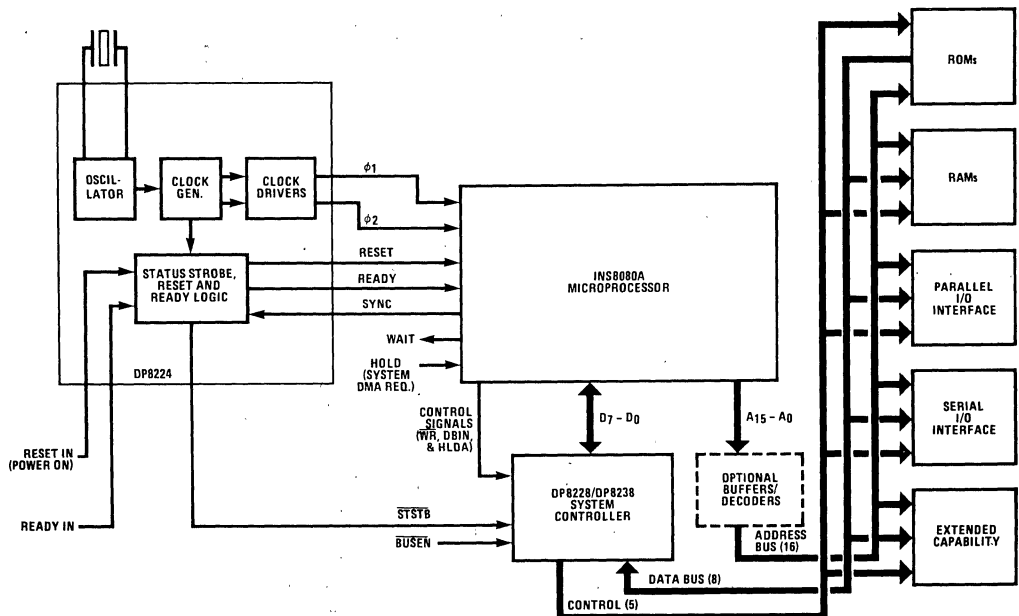
The DP8224 is a clock generator/driver contained in a standard, 16-pin dual-in-line package. The chip, which is fabricated using Schottky Bipolar technology, generates clocks and timing for National Semiconductor's N8080A microcomputer family.

Included in the DP8224 is an oscillator circuit that is controlled by an external crystal, which is selected by the designer to meet a variety of system speed requirements. Also included in the chip are circuits that provide: a status strobe for the DP8228 or DP8238 system controllers, power-on reset for the INS8080A microprocessor, and synchronization of the READY input to the INS8080A.

Features

- Crystal-Controlled Oscillator for Stable System Operation
- Single Chip Clock Generator and Driver for INS8080A Microprocessor
- Provides Status Strobe for DP8228 or DP8238 System Controllers
- Provides Power-On Reset for INS8080A Microprocessor
- Synchronizes READY Input to INS8080A Microprocessor
- Provides Oscillator Output for Synchronization of External Circuits
- Reduces System Component Count

N8080A Microcomputer Family Block Diagram



Absolute Maximum Ratings (Note 2)

Supply Voltage		
V _{CC}	7V	
V _{DD}	15V	
Input Voltage	-1V to +5.5V	
Storage Temperature Range	-65°C to +150°C	
Maximum Power Dissipation* at 25°C		
Cavity Package	1509 mW	
Molded Package	1476 mW	
Lead Temperature (Soldering, 10 seconds)	300°C	

*Derate cavity package 10.1 mW/°C above 25°C; derate molded package 11.8 mW/°C above 25°C.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage			
V _{CC}	4.75	5.25	V
V _{DD}	11.4	12.6	V
Temperature (T _A)	0	+70	°C

Electrical Characteristics (Note 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
I _F	Input Current Loading	V _F = 0.45V		-0.25	mA	
I _R	Input Leakage Current	V _R = 5.25V		10	μA	
V _C	Input Forward Clamp Voltage	I _C = -5 mA		-1.0	V	
V _{IL}	Input "Low" Voltage	V _{CC} = 5V		0.8	V	
V _{IH}	Input "High" Voltage	RESIN Input	2.6		V	
		All Other Inputs	2.0		V	
V _{IH} -V _{IL}	RESIN Input Hysteresis	V _{CC} = 5V	0.25		V	
V _{OL}	Output "Low" Voltage	(φ1, φ2), Ready, Reset, STSTB	I _{OL} = 2.5 mA		0.45	V
			I _{OL} = 10 mA		0.45	V
			I _{OL} = 15 mA		0.45	V
V _{OH}	Output "High" Voltage	φ1, φ2	I _{OH} = -100 μA	9.4		V
			I _{OH} = -100 μA	3.6		V
			I _{OH} = -1 mA	2.4		V
I _{SC}	Output Short-Circuit Current (All Low Voltage Outputs Only), (Note 1)	V _O = 0V, V _{CC} = 5V	-10		-60	mA
I _{CC}	Power Supply Current			115	mA	
I _{DD}	Power Supply Current			12	mA	

Note 1: Caution - φ1 and φ2 output drivers do not have short circuit protection.

Note 2: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 3: Unless otherwise specified min/max limits apply across the 0°C to +70°C range for the DP8224. All typical values are for T_A = 25°C, V_{CC} = 5V, and V_{DD} = 12V.

Crystal Requirements*

Tolerance	0.005% at 0°C to +70°C	Equivalent Resistance	75Ω to 20Ω
Resonance	Fundamental**	Power Dissipation (Min)	4 mW
Load Capacitance	20 pF to 30 pF		

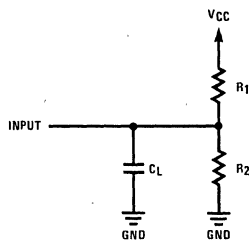
*It is good design practice to ground the case of the crystal

**With tank circuit, use 3rd overtone mode

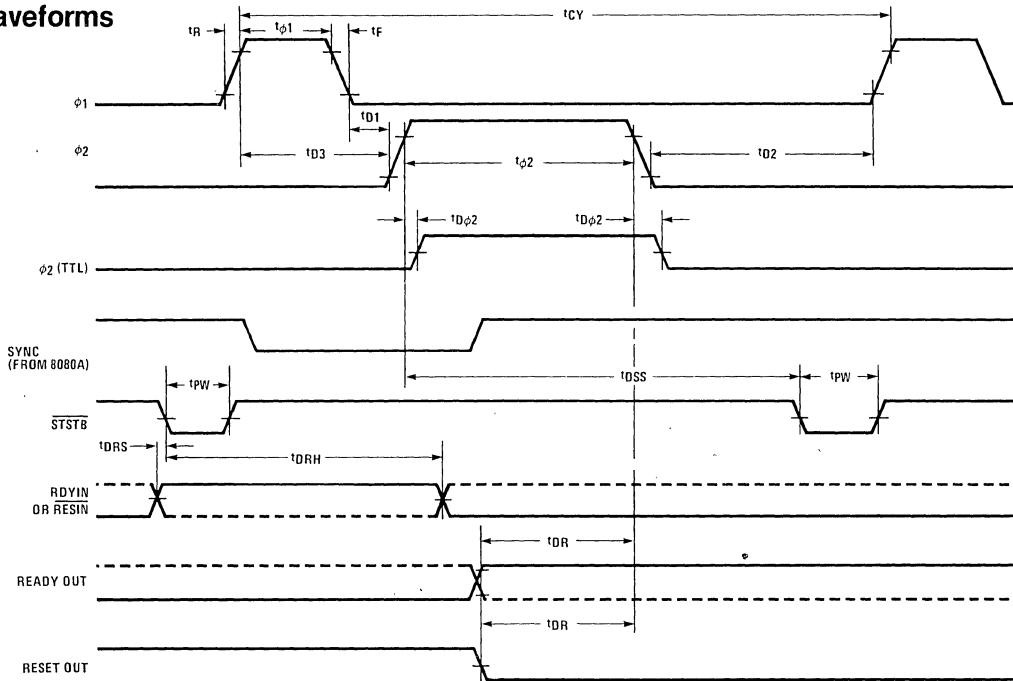
Switching Characteristics (Note 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t ϕ 1 ϕ 1 Pulse Width	C _L = 20 pF to 50 pF	$\frac{2t_{CY}}{9} - 20$			ns
t ϕ 2 ϕ 2 Pulse Width		$\frac{5t_{CY}}{9} - 35$			ns
tD1 ϕ 1 to ϕ 2 Delay		0			ns
tD2 ϕ 2 to ϕ 1 Delay		$\frac{2t_{CY}}{9} - 14$			ns
tD3 ϕ 1 to ϕ 2 Delay		$\frac{2t_{CY}}{9}$		$\frac{2t_{CY}}{9} + 20$	ns
t _r ϕ 1 and ϕ 2 Rise Time				20	ns
t _f ϕ 1 and ϕ 2 Fall Time				20	ns
tD ϕ 2 ϕ 2 to ϕ 2 (TTL) Delay	ϕ 2 TTL, C _L = 30 pF, R1 = 300 Ω , R2 = 600 Ω	-5		15	ns
tDSS ϕ 2 to \overline{STSTB} Delay	\overline{STSTB} , C _L = 15 pF R1 = 2 k Ω , R2 = 4 k Ω	$\frac{6t_{CY}}{9} - 30$		$\frac{6t_{CY}}{9}$	ns
tpw \overline{STSTB} Pulse Width		$\frac{t_{CY}}{9} - 15$			ns
tDRS RDYIN Set-Up Time to Status Strobe		$50 - \frac{4t_{CY}}{9}$			ns
tDRH RDYIN Hold Time After \overline{STSTB}		$\frac{4t_{CY}}{9}$			ns
tDR READY or RESET to ϕ 2 Delay	Ready and Reset, C _L = 10 pF, R1 = 2 k Ω , R2 = 4 k Ω	$\frac{4t_{CY}}{9} - 25$			ns
tCLK CLK Period			$\frac{t_{CY}}{9}$		ns
fMAX Maximum Oscillating Frequency		27			MHz
CIN Input Capacitance	VCC = 5V, VDD = 12V, VBIAS = 2.5V, f = 1 MHz			8	pF

Test Circuit



Waveforms



VOLTAGE MEASUREMENT POINTS: $\phi 1, \phi 2$ Logic "0" = 1.0V, Logic "1" = 8.0V. All other signals measured at 1.5V.

Switching Characteristics (For $t_{CY} = 488.28$ ns)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
$t_{\phi 1}$ $\phi 1$ Pulse Width	$\phi 1$ and $\phi 2$ Loaded to $C_L = 20$ to 50 pF Ready & Reset Loaded to 2 mA/ 10 pF All Measurements Referenced to 1.5 V unless Specified Otherwise	89			ns
$t_{\phi 2}$ $\phi 2$ Pulse Width		236			ns
t_{D1} Delay $\phi 1$ to $\phi 2$		0			ns
t_{D2} Delay $\phi 2$ to $\phi 1$		95			ns
t_{D3} Delay $\phi 1$ to $\phi 2$ Leading Edges		109		129	ns
t_r Output Rise Time				20	ns
t_f Output Fall Time				20	ns
t_{DSS} $\phi 2$ to \overline{STSTB} Delay		296		326	ns
$t_{D\phi 2}$ $\phi 2$ to $\phi 2$ (TTL) Delay		-5		15	ns
t_{PW} Status Strobe Pulse Width		40			ns
t_{DRS} RDYIN Set-Up Time to \overline{STSTB}		-167			ns
t_{DRH} RDYIN Hold Time after \overline{STSTB}		217			ns
t_{DR} READY or RESET to $\phi 2$ Delay		192			ns
f_{MAX} Oscillator Frequency			18.432	MHz	

Functional Pin Definitions

The following describes the function of all of the DP8224 input/output pins. Some of these descriptions reference internal circuits.

INPUT SIGNALS

Crystal Connections (XTAL 1 and XTAL 2): Two inputs that connect an external crystal to the oscillator circuit of the DP8224. Normally, a fundamental mode crystal is used to determine the basic operating frequency of the oscillator. However, overtone mode crystals may also be used. The crystal frequency is 9 times the desired microprocessor speed (that is, crystal frequency equals $1/t_{CY} \times 9$). When the crystal frequency is above 10 MHz, a selected capacitor (3 to 10 pF) may have to be connected in series with the crystal to produce the exact desired frequency. *Figure A.*

Tank: Allows the use of overtone mode crystals with the oscillator circuit. When an overtone mode crystal is used, the tank input connects to a parallel LC network that is ac coupled to ground. The formula for determining the resonant frequency of this LC network is as follows:

$$F = \frac{1}{2\pi\sqrt{LC}}$$

Synchronizing (SYNC) Signal: When high, indicates the beginning of a new machine cycle. The INS8080A microprocessor outputs a status word (which describes the current machine cycle) onto its data bus during the first state (SYNC interval) of each machine cycle.

Reset In (RESIN): Provides an automatic system reset and start-up upon application of power as follows. The RESIN input, which is obtained from the junction of an external RC network that is connected between V_{CC} and ground, is routed to an internal Schmitt Trigger circuit. This circuit converts the slow transition of the power supply rise into a sharp, clean edge when its input reaches a predetermined value. When this occurs, an internal D-type flip-flop is synchronously reset, thereby providing the RESET output signal discussed below.

For manual system reset, a momentary contact switch that provides a low (ground) when closed is also connected to the RESIN input.

Ready In (RDYIN): An asynchronous READY signal that is re-clocked by a D-type flip-flop of the DP8224 to provide the synchronous READY output discussed below.

+5 Volts: V_{CC} supply.

+12 Volts: V_{DD} supply.

Ground: 0 volt reference.

OUTPUT SIGNALS

Oscillator (OSC): A buffered oscillator signal that can be used for external timing purposes.

ϕ_1 and ϕ_2 Clocks: Two non-TTL compatible clock phases that provide nonoverlapping timing references for internal storage elements and logic circuits of the INS8080A microprocessor. The two clock phases are produced by an internal clock generator that consists of a divide-by-nine counter and the associated decode gating logic. *Figure B.*

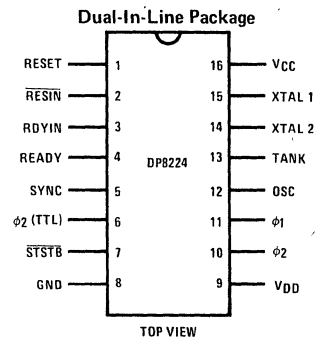
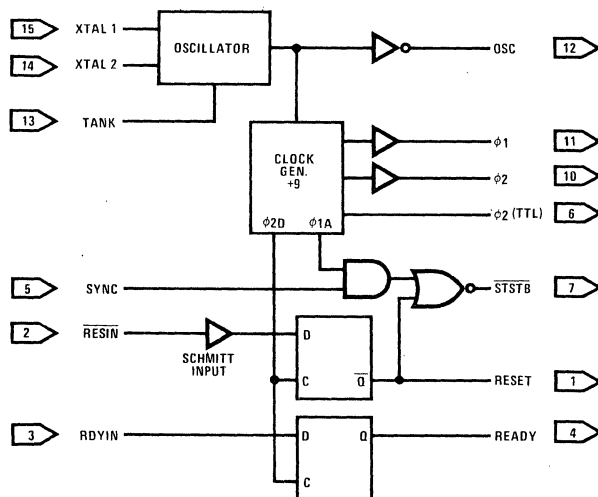
ϕ_2 (TTL) Clock: A TTL ϕ_2 clock phase that can be used for external timing purposes.

Status Strobe (STSTB): Activated (low) at the start of each new machine cycle. The STSTB signal is generated by gating a high-level SYNC input with the ϕ_{1A} timing signal from the internal clock generator of the DP8224. The STSTB signal is used to clock status information into the status latch of the DP8228 system controller and bus driver.

Reset: When the RESET signal is activated, the content of the program counter of the INS8080A is cleared. After RESET, the program will start at location 0 in memory.

Ready: The READY signal indicates to the INS8080A that valid memory or input data is available. This signal is used to synchronize the INS8080A with slower memory or input/output devices.

Logic and Connection Diagrams



Order Number DP8224J or DP8224N
See NS Package J16A or N16A

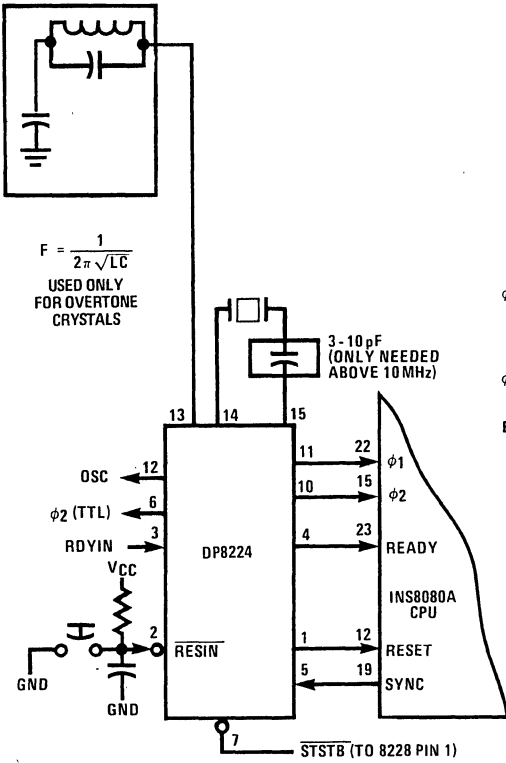
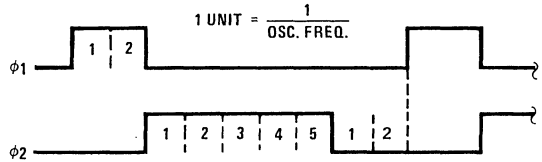


Figure A. DP8224 Connection Diagram



EXAMPLE: (8080 t_{CY} = 500 ns)

OSC = 18 mHz/55 ns

φ₁ = 110 ns (2 x 55 ns)

φ₂ = 275 ns (5 x 55 ns)

φ₂ - φ₁ = 110 ns (2 x 55 ns)

Figure B. DP8224 Clock Generator Waveforms

DP8228/DP8228M, DP8238/DP8238M System Controller and Bus Driver

General Description

The DP8228/DP8228M, DP8238/DP8238M are system controller/bus drivers contained in a standard, 28-pin dual-in-line package. The chip, which is fabricated using Schottky Bipolar technology, generates all the read and write control signals required to directly interface the memory and input/output components of National Semiconductor's INS8080A microcomputer family. The chip also provides drive and isolation for the bidirectional data bus of the INS8080A microprocessor. Data bus isolation enables the use of slower memory and input/output components in a system, and provides for enhanced system noise immunity.

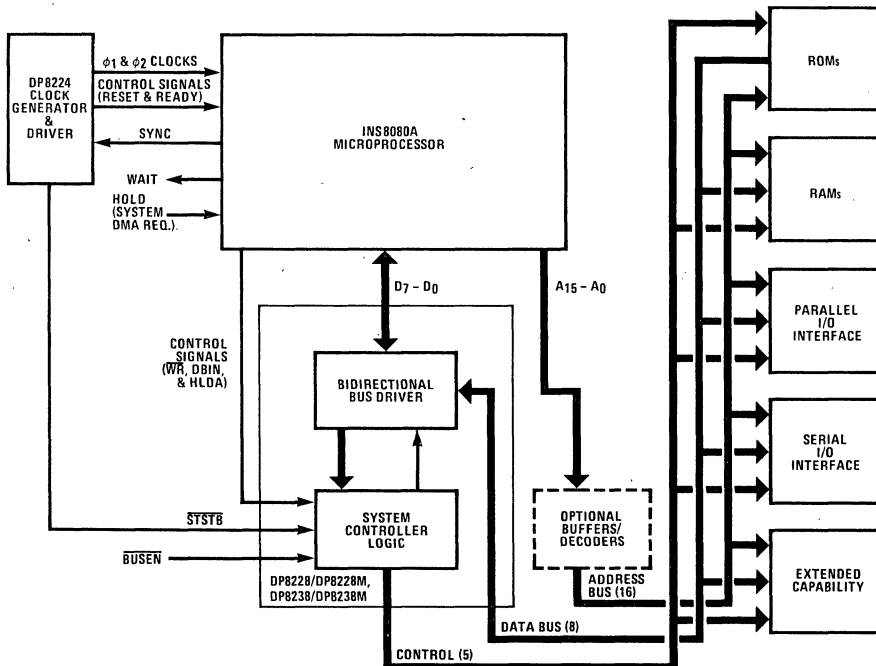
A user-selected single-level interrupt vector (RST 7) is provided by the device for use in the interrupt structure of small systems that need only one basic vector. No additional components (such as an interrupt instruction port) are required to use the single interrupt vector in these systems. The devices also generate an Interrupt Acknowledge (INTA) control signal for each byte of a multibyte CALL instruction when an interrupt is

acknowledged by the INS8080A. This feature permits the use of a multilevel priority interrupt structure in large, interrupt-driven systems.

Features

- Single Chip System Controller and Bus Driver for INS8080A Microcomputer Systems
- Allows Use of Multibyte CALL Instructions for Interrupt Acknowledge
- Provides User-Selected Single-Level Interrupt Vector (RST 7)
- Provides Isolation for Data Bus
- Supports A Wide Variety of System Bus Structures
- Reduces System Component Count
- DP8238/DP8238M Provides Advanced Input/Output Write and Memory Write Control Signals for Large System Timing Control

N8080A Microcomputer Family Block Diagram





Absolute Maximum Ratings

Storage Temperature	-65°C to +150°C
Supply Voltage, V _{CC}	-0.5V to +7V
Input Voltage	-1.5V to +7V
Output Current	100 mA
Maximum Power Dissipation* at 25°C	
Cavity Package	2179 mW
Molded Package	2361 mW

*Derate cavity package 14.5 mW/°C above 25°C; derate molded package 18.9 mW/°C above 25°C.

Note: Maximum ratings indicate limits beyond which permanent damage may occur. Continuous operation at these limits is not intended and should be limited to those conditions specified under DC electrical characteristics.

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{CC})			
DP8228M, DP8238M	4.50	5.50	V _{DC}
DP8228, DP8238	4.75	5.25	V _{DC}
Operating Temperature (T _A)			
DP8228M, DP8238M	-55	+125	°C
DP8228, DP8238	0	+70	°C

Electrical Characteristics

(Min ≤ T_A ≤ Max, Min ≤ V_{CC} ≤ Max, unless otherwise noted)

PARAMETER		CONDITIONS	MIN	TYP (Note 1)	MAX	UNITS
V _C	Input Clamp Voltage, All Inputs	V _{CC} = Min, I _C = -5 mA		0.6	-1.0	V
I _F	Input Load Current STSTB D2 and D6 D0, D1, D4, D5 and D7 All Other Inputs	V _{CC} = Max				
		V _F = 0.45V for DP8228, DP8238			500	μA
		V _F = 0.40V for DP8228M, DP8238M			750	μA
					250	μA
I _R	Input Leakage Current DB0-DB7 All Other Inputs	V _{CC} = Max, V _R = V _{CC}			20	μA
					100	μA
V _{TH}	Input Threshold Voltage, All Inputs	V _{CC} = 5V	0.8		2.0	V
I _{CC}	Power Supply Current	V _{CC} = Max	DP8228, DP8238	160	190	mA
			DP8228M, DP8238M	160	210	mA
V _{OL}	Output Low Voltage D0-D7	V _{CC} = Min, I _{OL} = 2 mA	DP8228M, DP8238M		0.50	V
			DP8228, DP8238		0.45	V
	All Other Outputs	V _{CC} = Min, I _{OL} = 10 mA	DP8228M, DP8238M		0.50	V
			DP8228, DP8238		0.45	V
V _{OH}	Output High Voltage D0-D7	V _{CC} = Min, I _{OH} = -10 μA	DP8228M, DP8238M	3.3	3.8	V
			DP8228, DP8238	3.6	3.8	V
	All Other Outputs	V _{CC} = Min, I _{OH} = -1 mA	2.4	3.8	V	
I _{OS}	Short Circuit Current, All Outputs	V _{CC} = 5V, V _O = 0V	15		90	mA
I _{O(OFF)}	OFF State Output Current All Control Outputs	V _{CC} = Max, V _O = V _{CC}			100	μA
		V _{CC} = Max, V _O = 0.45V			-100	μA
I _{INT}	INTA Current	(See Test Conditions, Figure 3)			5	mA

Note 1: Typical values are for T_A = 25°C and typical supply voltages.

Capacitance

V_{BIAS} = 2.5V, V_{CC} = 5.0V, T_A = 25°C, f = 1 MHz.

PARAMETER	MIN	TYP (Note 1)	MAX	UNITS
C _{IN}	Input Capacitance	8	12	pF
C _{OUT}	Output Capacitance Control Signals	7	15	pF
I/O	I/O Capacitance (D or DB)	8	15	pF

This parameter is periodically sampled and not 100% tested.

Switching Characteristics

(Min $\leq V_{CC} \leq$ Max, Min $\leq T_A \leq$ Max)

PARAMETER	CONDITIONS	DP8228M, DP8238M		DP8228, DP8238		UNITS	
		MIN	MAX	MIN	MAX		
tPW	Width of Status Strobe	25		22		ns	
tSS	Set-Up Time, Status Inputs D0–D7	8		8		ns	
tSH	Hold Time, Status Inputs D0–D7	5		5		ns	
tDC	Delay from \overline{STSTB} to Any Control Signal	(Figure 2)	20	75	20	60	ns
tRR	Delay from DBIN to Control Outputs	(Figure 2)		30		30	ns
tRE	Delay from DBIN to Enable/Disable 8080 Bus	(Figure 1)		45		45	ns
tRD	Delay from System Bus to 8080 Bus during Read	(Figure 1)		45		30	ns
tWR	Delay from \overline{WR} to Control Outputs	(Figure 2)	5	60	5	45	ns
tWE	Delay to Enable System Bus DB0–DB7 after \overline{STSTB}	(Figure 2)		30		30	ns
tWD	Delay from 8080 Bus D0–D7 to System Bus DB0–DB7 during Write	(Figure 2)	5	40	5	40	ns
tE	Delay from System Bus Enable to System Bus DB0–DB7	(Figure 2)		30		30	ns
tHD	HLDA to Read Status Outputs	(Figure 2)		25		25	ns
tDS	Set-Up Time, System Bus Inputs to HLDA		10		10		ns
tDH	Hold Time, System Bus Inputs to HLDA		20		20		ns

Test Conditions

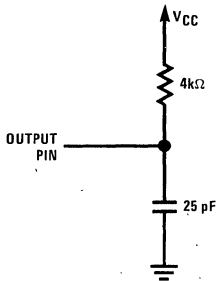


FIGURE 1. Test Load

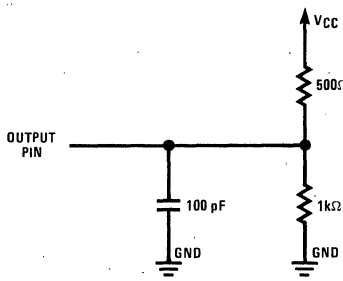


FIGURE 2. Test Load

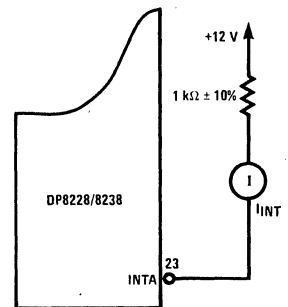
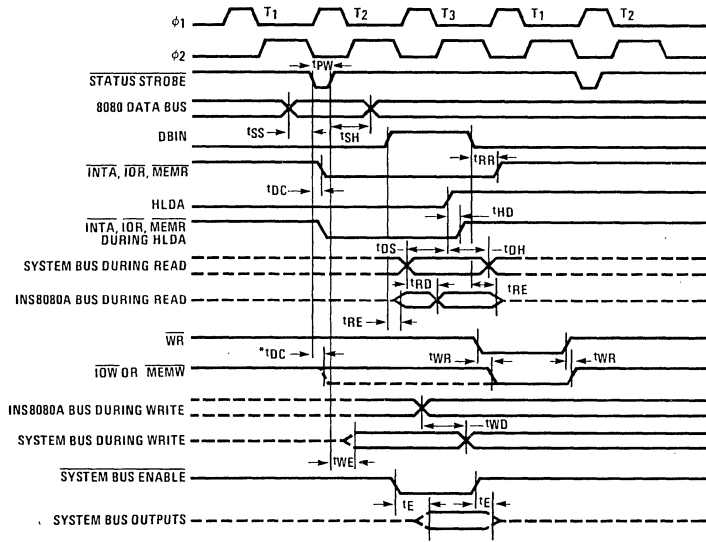


FIGURE 3. INTA Test Circuit (For RST 7)

Timing Diagram



VOLTAGE MEASUREMENT POINTS: D₀ - D₇ (when outputs) Logic "0" = 0.8 V, Logic "1" = 3.0 V. All other signals measured at 1.5 V.

*Advanced I/OW MEMW for 8238 only.

Functional Pin Definitions

The following describes the function of all of the DP8228/DP8228M, DP8238/DP8238M pinouts. Some of these descriptions reference internal circuits.

INPUT SIGNALS

Status Strobe (STSTB): Activated (low) at the start of each new machine cycle. The STSTB input is used to store a status word (refer to chart) from the INS8080A microprocessor into the internal status latch of the DP8228, DP8238. The status word is latched when the STSTB returns to the high state. The INS8080A outputs this status word onto its data bus during the first state (SYNC interval) of each machine cycle.

Data Bus In (DBIN): When high, indicates that the INS8080A data bus is in the input mode. The DBIN signal is used to gate data from memory or an input/output device onto the data bus.

Write (WR): When low, indicates that the data on the INS8080A data bus are stable for WRITE memory or output operation.

Hold Acknowledge (HLDA): When high, indicates that the INS8080A data and address buses will go to their high impedance state. When in the data bus read mode, DBIN input in the high state, a high HLDA input will latch the data bus information into the driver circuits and gate off the applicable control signal I/OR, MEMR, or INTA (return to the output high state).

Bus Enable (BUSEN): Asynchronous DMA input to the internal gating array. When low, normal operation of the internal bidirectional bus driver and gating array occurs. When high, the bus driver and gating array are driven to their high impedance state.

V_{CC} Supply: +5 volts.

Ground: 0 volt reference.

OUTPUT SIGNALS

Memory Read (MEMR): When low, signals data to be loaded in from memory. The MEMR signal is generated by strobing in status word 1, 2, or 4. (Refer to status word chart.)

Memory Write (MEMW): When low, signals data to be stored in memory. The MEMW signal is generated for the DP8238 by strobing in status word 3 or 5. (Refer to status word chart.) For the DP8228, the MEMW signal is generated by gating a low-level WR input with the strobed in status word 3 or 5.

Input/Output Read (I/OR): When low, signals data to be loaded in from an addressed input/output device. The I/OR signal is generated by strobing in status word 6.

Input/Output Write (I/OW): When low, signals data to be transferred to an addressed input/output device. The I/OW signal for the DP8238 is generated by strobing in status word 7. For the DP8228 the I/OW signal is generated by gating in a low-level WR input with the strobed in status word 7.

Interrupt Acknowledge (INTA): When low, indicates that an interrupt has been acknowledged by the INS8080A microprocessor. The INTA signal is generated by strobing in status word 8 or 10.

Single Level Interrupt (RST 7): When the INTA output is tied to 12 V through a 1 kΩ resistor, strobing in status word 8 or 10 will cause the CPU data bus outputs, when active, to go to the high state.

INPUT/OUTPUT SIGNALS

CPU Data (D₇ - D₀) Bus: This bus comprises eight TRI-STATE input/output lines that connect to the INS8080A microprocessor. The bus provides bidirec-



Functional Pin Definitions (Continued)

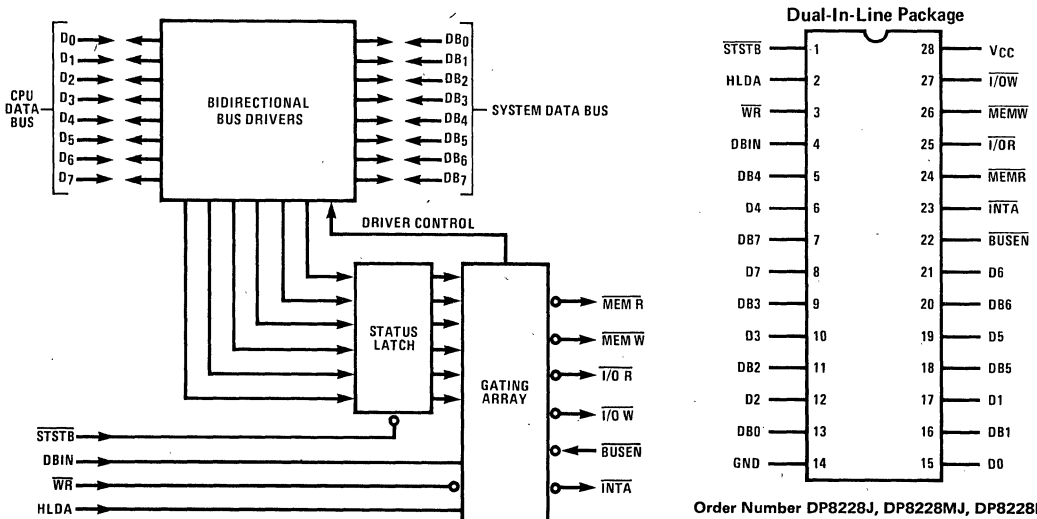
tional communication between the CPU, memory, and input/output devices for instructions and data transfers. A status word (which describes the current machine cycle) is also outputted on this data bus during the first microcycle of each machine cycle (SYNC = logic 1).

System Data (DB₇-DB₀) Bus: This bus comprises eight TRI-STATE input/output lines that connect to the memory and input/output components of the system. The internal bidirectional bus driver isolates the DB₇-DB₀ Data Bus from the D₇-D₀ Data Bus.

Status Word Chart

Machine Cycle	Status Word	Data Bus Bit								Control Signal
		D ₇	D ₆	D ₅	D ₄	D ₃	D ₂	D ₁	D ₀	
Instruction Fetch	1	1	0	1	0	0	0	1	0	$\overline{\text{MEMR}}$
Memory Read	2	1	0	0	0	0	0	1	0	$\overline{\text{MEMR}}$
Memory Write	3	0	0	0	0	0	0	0	0	$\overline{\text{MEMW}}$
Stack Read	4	1	0	0	0	0	1	1	0	$\overline{\text{MEMR}}$
Stack Write	5	0	0	0	0	0	1	0	0	$\overline{\text{MEMW}}$
Input Read	6	0	1	0	0	0	0	1	0	$\overline{\text{I/OR}}$
Output Write	7	0	0	0	1	0	0	0	0	$\overline{\text{I/OW}}$
Interrupt Acknowledge	8	0	0	1	0	0	0	1	1	$\overline{\text{INTA}}$
Halt Acknowledge	9	1	0	0	0	1	0	1	0	(none)
Interrupt Acknowledge While Halt	10	0	0	1	0	1	0	1	1	$\overline{\text{INTA}}$

Block and Connection Diagrams



Order Number DP8228J, DP8228MJ, DP8228N,
 DP8238J, DP8238MJ or DP8238N
 See NS Package J28A or N28A



Section 9 Data Communications Support



DEVICE	DESCRIPTION	PAGE NUMBER
DP8340	Serial Bi-Phase Transmitter/Encoder	9-3
DP8341	Serial Bi-Phase Receiver/Decoder	9-12
DP8342	High-Speed Serial Transmitter/Encoder	9-23
DP8343	High-Speed Serial Receiver/Decoder	9-32

DP8340 Serial Bi-Phase Transmitter/Encoder

General Description

The DP8340 generates a complete encoding of parallel data for high speed serial transmission which conforms to the protocol as defined by the IBM 3270 information display system standard. The DP8340 converts parallel input data into a serial data stream. Although the IBM standard covers bi-phase serial data transmission over a coax line, the DP8340 also adapts to general high speed serial data transmission over other than coax lines, at frequencies either higher or lower than the IBM standard.

The DP8340 and its complementary chip, the DP8341 (receiver/decoder) have been designed to provide maximum flexibility in system designs. The separation of the transmitter/receiver functions provides convenient addition of more receivers at one end of a bi-phase line without the need of unused transmitters. This is specifically advantageous in control units where typical bi-phase data is multiplexed over many bi-phase lines and the number of receivers generally exceeds the number of transmitters.

Features

- Ten bits per data byte transmission
- Single-byte or multi-byte transmission
- Internal parity generation (even or odd)
- Internal crystal controlled oscillator used for the generation of all required chip timing frequencies
- Clock output directly drives receiver (DP8341) clock input
- Input data holding register
- Automatic clear status response feature
- Line drivers at data outputs provide easy interface to bi-phase coax line or general transmission lines
- <2ns driver output skew
- Bipolar technology provides TTL input/output compatibility
- Data outputs power up/down glitch free
- Internal power up clear and reset
- Single +5V power supply

Connection Diagram

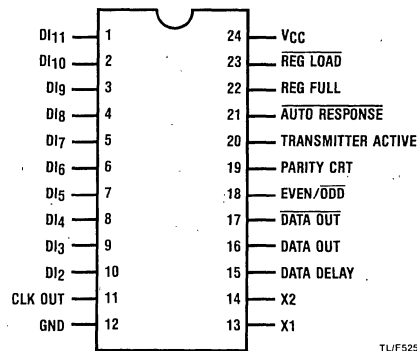


FIGURE 1. Pin-Out Diagram

Order Number DP8340J or DP8340N
See NS Package J24A or N24A

Block Diagram

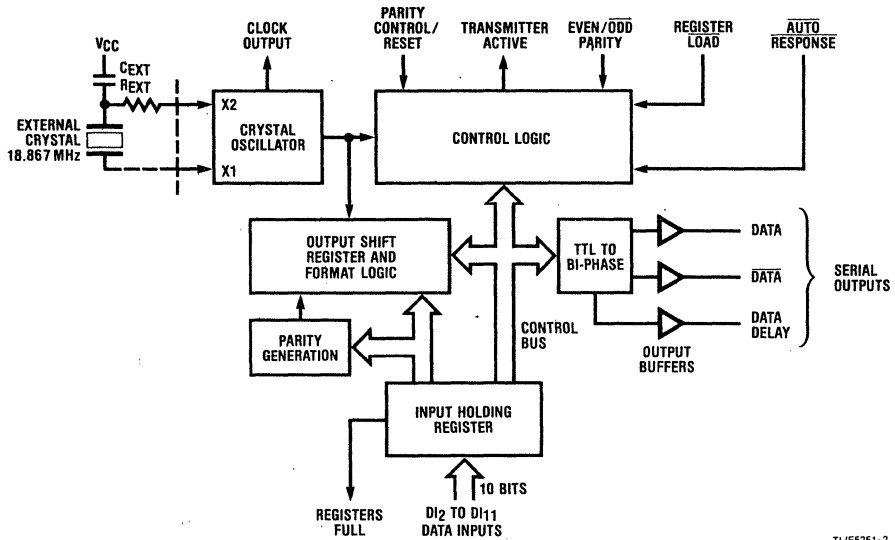


FIGURE 2. DP8340 Serial Bi-Phase Transmitter/Encoder Block Diagram

Block Diagram Functional Description

Figure 2 is a block diagram of the DP8340 Bi-Phase Transmitter/Encoder. The transmitter/encoder contains a crystal oscillator whose input is a crystal with a frequency eight (8) times the data rate. A Clock Output is provided to drive the DP8341 receiver/decoder Clock Input and other system components at the oscillator frequency. Additionally, the oscillator drives the control logic and output shift register/format logic blocks.

Data is parallel loaded from the system data bus to the transmitter/encoder's input holding register. This data is in turn loaded by the transmitter/encoder to its output shift register if this register was empty at the time of the load. During this load, message formatting and parity are generated. The formatted message is then shifted out at the bit rate frequency to the TTL to Bi-Phase block which generates the proper data bit formatting. The three data outputs, DATA, $\overline{\text{DATA}}$, and DATA DELAY provide for flexible interface to the coax line with a minimum of external components.

The Control Logic block interfaces to all blocks to insure proper chip operation and sequencing. It controls the type of parity generation through the Even/Odd Parity input. An additional feature provided by the transmitter/encoder is generation of odd parity and placement in bit 10 position while still maintaining even or odd parity in

the bit 12 position. This is the format of data word bytes and other commands in the 3270 Standard. The Parity Control input is the pin which controls when this operation is in effect.

Another feature of the transmitter/encoder is the internal TT/AR (Transmission Turnaround/Auto Response) capability. After each Write type message from the control unit in the 3270 Standard, the receiving unit must respond with clean status (bits 2 through 11). With the transmitter/encoder this function is accomplished simply by forcing the Auto-Response input to the Logic "0" state.

Operation of the transmitter/encoder is automatic. After the first data byte is loaded, the Transmitter Active output is set and the transmitter/encoder immediately formats the input data and serially shifts it out its data outputs. If the message is a multi-byte message, the internal format logic will modify the message data format for multibyte as long as the next byte is loaded to the input holding register before the last data bit of the previous data byte is transferred out of the internal output shift register. After all data is shifted out of the transmitter/encoder the Transmitter Active output will return to the inactive state.

Detailed Pin/Functional Description

Crystal Inputs X1 and X2

The oscillator is controlled by an external, parallel resonant crystal connected between the X1 and X2 pins. Normally, a fundamental mode crystal is used to determine the operating frequency of the oscillator; however, overtone mode crystals may be used.

Crystal Specifications (Parallel Resonant)

Type	AT-cut crystal
Tolerance	0.005% at 25°C
Stability	0.01% from 0°C to +70°C
Resonance	Fundamental (Parallel)
Maximum Series Resistance	Dependent on Frequency (For 18.867 MHz, 50Ω)
Load Capacitance	15pF

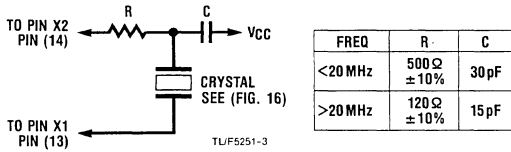


FIGURE 3. Connection Diagram

If the DP8340 transmitter is clocked by a system clock (crystal oscillator not used), pin 13 (X1 input) should be clocked directly using a Schottky series (74S) circuit. Pin 14 (X2 input) may be left open. The clocking frequency must be set at eight times the data bit rate. Maximum input frequency is 28 MHz. For the IBM 3270 Interface, this frequency is 18.867 MHz. At this frequency, the serial bit rate will be 2.358 Mb/Sec.

Clock Output

The Clock Output is a buffered output derived directly from the crystal oscillator block and clocks at the oscillator frequency. It is designed to directly drive the DP8341 receiver/decoder Clock Input as well as other system components.

Registers Full

This output is used as a flag by the external operating system. A logic "1" (active state) on this output indicates that both the internal output shift register and the input holding register contain active data. No additional data should be loaded until this output returns to the logic "0" state (inactive state).

Transmitter Active

This output will be in the logic "1" state while the transmitter/encoder is about to transmit or in the process of transmitting data. Otherwise, it will assume the logic "0" state indicating no data presently in either the input holding or output shift registers.

Register Load

The Register Load input is used to load data from the Data Inputs to the input holding register. The loading

function is edge sensitive, the data present during the logic "0" state of this input is loaded, and the input data must be valid before the logic "0" to logic "1" transition. It is after this transition that the transmitter/encoder begins formatting of data for serial transmission.

Auto Response (TT/AR)

This input provides for automatic clear data transmission (all bits in logic "0") without the need of loading all zero's. When a logic "0" is forced on this input the transmitter/encoder immediately responds with transmission of "clean status". This function is necessary after the completion of each write type command and in other functions in the 3270 specification. In the logic "1" state the transmitter/encoder transmits data entered on the Data Inputs.

Even/Odd Parity

This input sets the internal logic of the DP8340 transmitter/encoder to generate either even or odd parity for the data byte in the bit 12 position. When this pin is in the logic "0" state odd parity is generated. In the logic "1" state even parity is generated. This feature is useful when the control unit is performing a loop back check and at the same time the controller wishes to verify proper data transmission with its receiver/decoder.

Parity Control/Reset

Depending on the type of message transmitted, it is at times necessary in the IBM 3270 specification to generate an additional parity bit in the bit 10 position. The bit generated is odd parity on the previous eight (8) bits of data. When the Parity Control input is in the logic "1" state the data entered at the Data Bit 10 position is placed in the transmitted word. With the Parity Control input in the logic "0" state the Data Bit 10 input is ignored and odd parity on the previous data bits is placed in the normal bit 10 position while overall word parity (bit 12) is even or odd (controlled by Even/Odd Parity input). This eliminates the need for external logic to generate the parity on the data bits.

Truth Table

Parity Control Input	Transmitted Data Bit 10
Logic "1"	Data entered on Data Input 10
Logic "0"	Odd Parity on 8-bit data byte

When this input is driven to a voltage that exceeds the power supply level (7V to 13V) the transmitter/encoder is reset.

Serial Outputs — DATA, $\overline{\text{DATA}}$, and DATA DELAY

These three output pins provide for convenient application of data to the Bi-Phase Coax line (see Figure 15 for application). The Data outputs are a direct bit representation of the Bi-Phase data while the DATA DELAY output provides the necessary increment to clearly define the four (4) DC levels of the pulse. The DATA and $\overline{\text{DATA}}$ outputs add flexibility to the DP8340 transmitter/encoder for use in high speed differential line driving applications.

Functional Timing Waveforms — Message Format

Single Byte Transmission

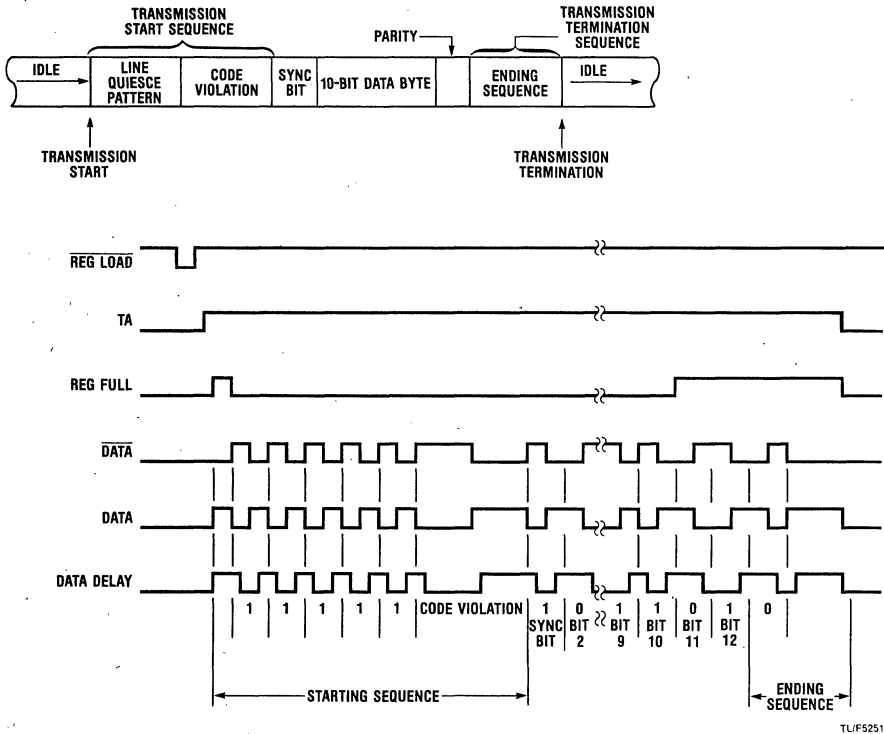


FIGURE 4. Overall Timing Waveforms for Single Byte

Multi-Byte Transmission

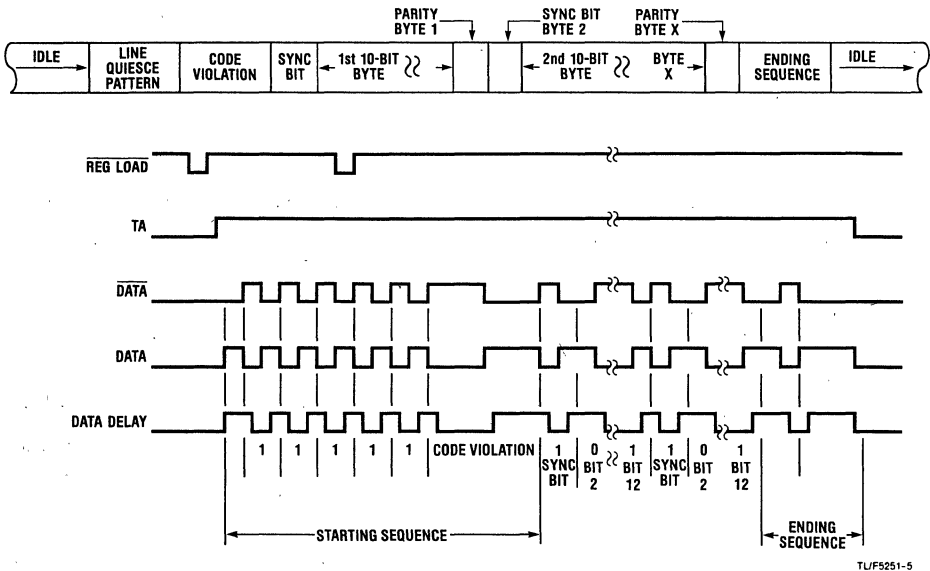


FIGURE 5. Overall Timing Waveforms for Multi-Byte

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7V
Input Voltage	5.5V
Output Voltage	5.25V
Storage Temperature Range	-65°C to 150°C
Lead Temperature (soldering, 10 seconds)	300°C
Maximum Power Dissipation* at 25°C	
Cavity Package	2237 mW
Molded Package	2500 mW

* Derate cavity package 14.9 mW/°C above 25°C; derate molded package 20 mW/°C above 25°C.

Operating Conditions

	Min.	Max.	Units
Supply Voltage, (V_{CC})	4.75	5.25	V
Ambient Temperature, T_A	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V_{IH}	Logic "1" Input Voltage (All Inputs Except X1 and X2)		2.0			V
V_{IL}	Logic "0" Input Voltage (All Inputs Except X1 and X2)				0.8	V
V_{CLAMP}	Input Clamp Voltage (All Inputs Except X1 and X2)	$I_{IN} = -12\text{ mA}$		-0.8	-1.2	V
I_{IH}	Logic "1" Input Current Register Load Input	$V_{CC} = 5.25\text{V}$ $V_{IN} = 5.25\text{V}$		0.3	120	μA
	All Others Except X1 and X2			0.1	40	μA
I_{IL}	Logic "0" Input Current Register Load Input	$V_{CC} = 5.25\text{V}$ $V_{IN} = 0.5\text{V}$		-15	-300	μA
	All Inputs Except X1 and X2			-5	-100	μA
V_{OH1}	Logic "1" All Outputs Except CLK OUT, DATA, $\overline{\text{DATA}}$, and DATA DELAY	$I_{OH} = -100\mu\text{A}$	3.2	3.9		V
		$I_{OH} = -1\text{ mA}$	2.5	3.4		V
V_{OH2}	Logic "1" for CLK OUT, DATA, $\overline{\text{DATA}}$ and DATA DELAY Outputs	$I_{OH} = -10\text{ mA}$	2.6	3.0		V
V_{OL1}	Logic "0" All Outputs Except CLK OUT, DATA, $\overline{\text{DATA}}$, and DATA DELAY			0.35	0.5	V
V_{OL2}	Logic "0" for CLK OUT, DATA, $\overline{\text{DATA}}$ and DATA DELAY Outputs	$I_{OL} = 20\text{ mA}$		0.4	0.6	V
I_{OS1}	Short Circuit Current for All Outputs Except CLK OUT, DATA, $\overline{\text{DATA}}$, and DATA DELAY	$V_{OUT} = 0\text{V}$ Note 4	-10	-30	-100	mA
I_{OS2}	Short Circuit Current for DATA, $\overline{\text{DATA}}$, and DATA DELAY Outputs	$V_{OUT} = 0\text{V}$ Note 4	-50	-140	-250	mA
I_{OS3}	Short Circuit Current for CLK OUT	Note 4	-30	-90	-200	mA
I_{CC}	Power Supply Current	$V_{CC} = 5.25\text{V}$		170	250	mA

Timing Characteristics Oscillator Frequency = 18.867 MHz (Notes 2 and 3)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
t_{pd1}	$\overline{\text{REG LOAD}}$ to Transmitter Active (T_A) Positive Edge	Load Circuit 1 Figure 7		60	90	ns
t_{pd2}	$\overline{\text{REG LOAD}}$ to REG FULL; Positive Edge	Load Circuit 1 Figure 7		45	75	ns
t_{pd3}	Register Full to T_A ; Negative Edge	Load Circuit 1 Figure 7		40	70	ns
t_{pd4}	Positive Edge of $\overline{\text{REG LOAD}}$ to Positive Edge of DATA	Load Circuits 1 & 2 Figure 9		50	80	ns
t_{pd5}	$\overline{\text{REG LOAD}}$ to $\overline{\text{DATA}}$; Positive Edge	Load Circuits 1 & 2 Figure 9, Note 6		380	475	ns
t_{pd6}	$\overline{\text{REG LOAD}}$ to DATA DELAY; Positive Edge	Load Circuits 1 & 2 Figure 9, Note 6		160	250	ns

Timing Characteristics (Continued) Oscillator Frequency = 18.867MHz (Notes 2 and 3)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
t_{pd7}	Positive Edge of \overline{DATA} to Negative Edge of DATA DELAY	Load Circuit 2 Figure 9, Note 6		100	115	ns
t_{pd8}	Positive Edge of DATA DELAY to Negative Edge of \overline{DATA}	Load Circuit 2 Figure 9, Note 6		110	125	ns
t_{pd9} , t_{pd10}	Skew between DATA and \overline{DATA}	Load Circuit 2 Figure 9		2	6	ns
t_{pd11}	Negative Edge of Auto Response to Positive Edge of TA	Load Circuit 1 Figure 10		70	110	ns
t_{pd12}	Maximum Time Delay to Load Second Byte After Positive Edge of REG FULL	Load Circuit 1 Figure 8, Note 6			$4 \times T - 50$	ns
t_{pd13}	X1 to CLK OUT; Positive Edge	Load Circuit 2 Figure 13		21	30	ns
t_{pd14}	X1 to CLK OUT; Negative Edge	Load Circuit 2 Figure 13		23	33	ns
t_{pd15}	Negative Edge of AR to Positive Edge of REG FULL	Load Circuit 1 Figure 10		45	75	ns
t_{pd16}	Skew between TA and REG FULL during Auto Response	Load Circuit 1 Figure 10		50	80	ns
t_{pd17}	$\overline{REG\ LOAD}$ to REG FULL; Positive Edge for Second Byte	Load Circuit 1 Figure 14		45	75	ns
t_{pw1}	$\overline{REG\ LOAD}$ Pulse Width	Figure 12	40			ns
t_{pw2}	First REG FULL Pulse Width (note 5)	Load Circuit 1 Figure 7, Note 6		$8 \times T + 60$	$8 \times T + 100$	ns
t_{pw3}	REG FULL Pulse Width Prior to Ending Sequence (Note 5)	Load Circuit 1, Figure 7, Note 6		$5 \times B$		ns
t_{pw4}	Pulse Width for Auto Response	Figure 10	40			ns
t_S	Data Setup Time prior to $\overline{REG\ LOAD}$ Positive Edge. Hold Time (t_H) = 0 ns	Figure 12		15	25	ns
t_{r1}	Rise Time for DATA, \overline{DATA} , and DATA DELAY Output Waveform	Load Circuit 2 Figure 11		7	13	ns
t_{f1}	Fall Time for DATA, \overline{DATA} , and DATA DELAY Output Waveform	Load Circuit 2 Figure 11		5	11	ns
t_{r2}	Rise Time for TA and REG FULL	Load Circuit 1 Figure 15		20	30	ns
t_{f2}	Fall Time for TA and REG FULL	Load Circuit 1 Figure 15		15	25	ns
f_{MAX}	Data Rate Frequency (Clock Input must be 8X this Frequency)	Note 7	DC		3.5	Mbits/s

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min./max. limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0\text{V}$.

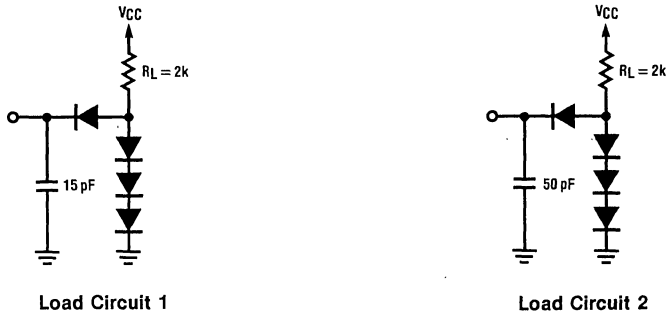
Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max. or min. are so classified on absolute basis.

Note 4: Only one output should be shorted at a time.

Note 5: $T = 1/(\text{Oscillator Frequency})$, unit for T should be ns. $B = 8T$

Note 6: Oscillator Frequency Dependent.

Note 7: For the IBM 3270 Interface, the data rate frequency is 2.358 Mbits/s.



TUF5251-6

FIGURE 6. Test Load Circuits

Timing Waveforms

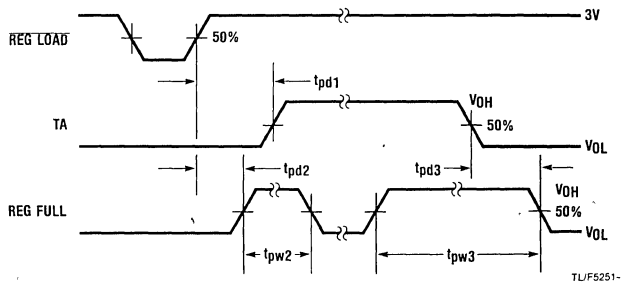


FIGURE 7. Timing Waveforms for Single Byte Transfer

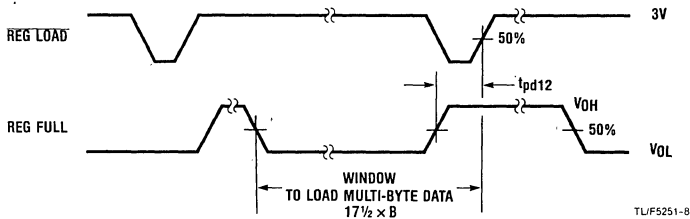


FIGURE 8. Maximum Window to Load Multi-Byte Data

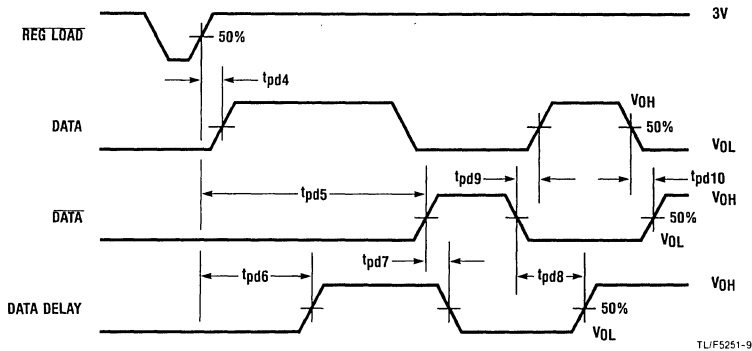


FIGURE 9. Timing Waveforms for Three Serial Outputs

Timing Waveforms (Continued)

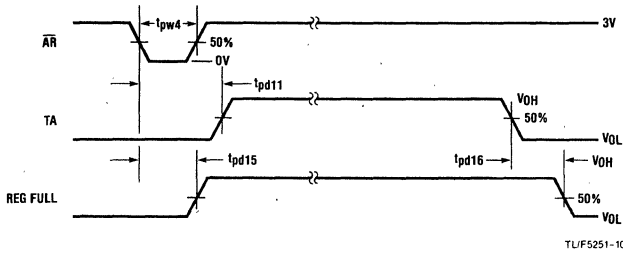


FIGURE 10. Timing Waveforms for Auto-Response

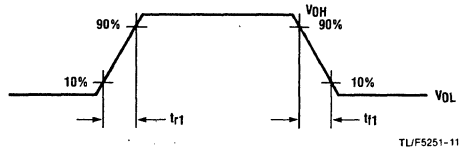


FIGURE 11. Output Waveform for DATA, DATA, DATA DELAY (Load Circuit 2)

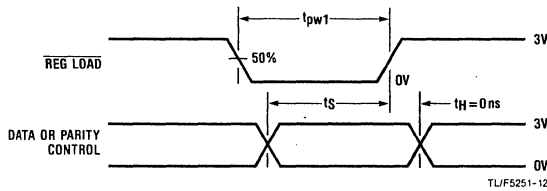


FIGURE 12. Register Load Waveform Requirement

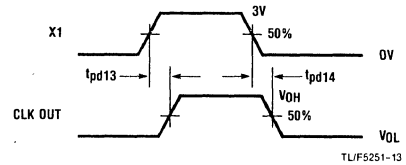


FIGURE 13. Timing Waveforms For Clock Pulse

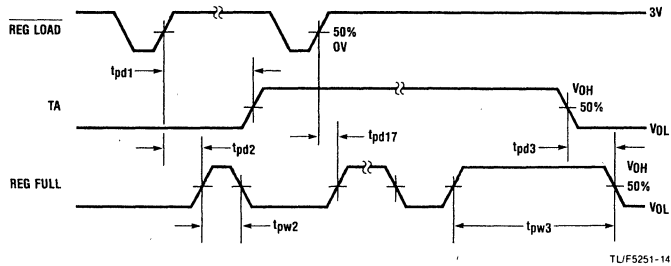


FIGURE 14. Timing Waveforms For Two Byte Transfer

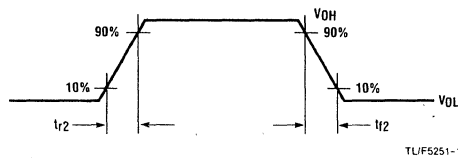
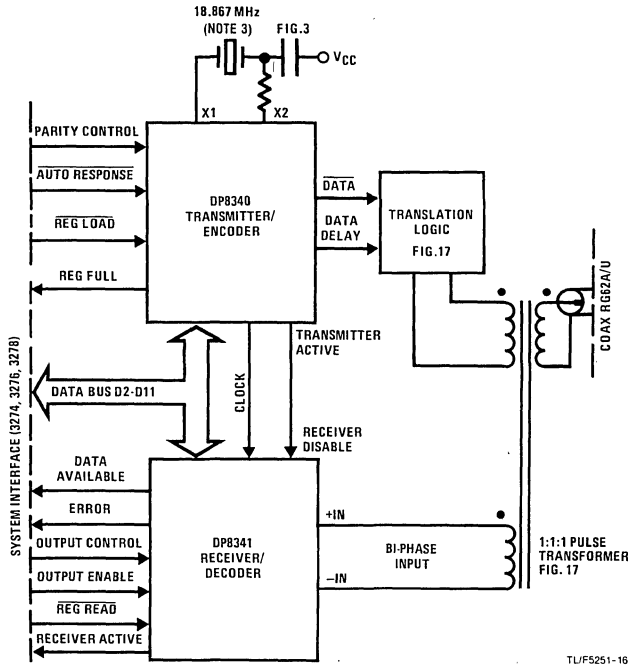


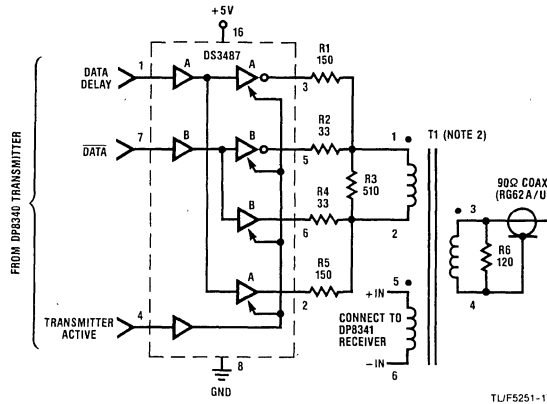
FIGURE 15. Rise and Fall Time Measurement for TA and REG Full

Typical Applications



TUF5251-16

FIGURE 16. Typical Application For IBM 3270 Interface



TUF5251-17

- Notes:
- 1) Resistance values are in ohms, $\pm 5\%$, $\frac{1}{4}W$
 - 2) T1 is a 1:1:1 pulse transformer, $L_{MIN} = 500\mu H$ for 18MHz system clock Pulse Engineering Part No. 5763 Technitrol Part No. 11LHA or equivalent transformers
 - 3) Crystal manufacturer Midland Ross Corp. NEL Unit Part No. NE-18A @ 18.867MHz.

FIGURE 17. Translation Logic

DP8341 Serial Bi-Phase Receiver/Decoder

General Description

The DP8341 provides complete decoding of data for high speed serial data communications. In specific, the DP8341 recognizes serial data that conforms to the IBM 3270 Information Display System Standard and converts it into ten (10) bits of parallel data. Although this standard covers Bi-Phase serial data transmission over a coax line, this device easily adapts to generalized high speed serial data transmission on other than coax lines at frequencies either higher or lower than the IBM 3270 standard.

The DP8341 receiver and its complementary chip, the DP8340 transmitter, are designed to provide maximum flexibility in system designs. The separation of transmitter and receiver functions allows addition of more receivers at one end of the Bi-Phase line without the necessity of adding unused transmitters. This is advantageous specifically in control units where typically Bi-Phase data is multiplexed over many Bi-Phase lines and the number of receivers generally outnumber the number of transmitters. The separation of transmitter and receiver function provides an additional advantage in flexibility of data bus organization. The data bus outputs of the receiver are TRI-STATE[®], thus enabling the bus configuration to be organized as either a common transmit/receive (bi-directional) bus or as separate transmit and receive busses for higher speed.

Features

- DP8341 receives ten (10) bit data bytes and conforms to the IBM 3270 Interface Display System Standard
- Separate receiver and transmitter provide maximum system design flexibility
- Even parity detection
- High sensitivity input on receiver easily interfaces to coax line
- Standard TTL data input on receiver provides generalized transmission line interface and also provides hysteresis
- Data holding register
- Multi-byte or single byte transfers
- TRI-STATE receiver data outputs provide flexibility for common or separated transmit/receive data bus operation.
- Data transmission error detection on receiver provides for both error detection and error type definition
- Bi-polar technology provides TTL input/output compatibility with excellent drive characteristics
- Single +5V power supply operation

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Connection Diagram

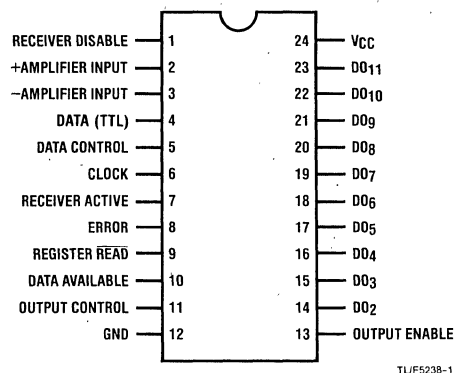


FIGURE 1. Pin-Out Diagram

Order Number DP8341J or DP8341N
See NS Package J24A or N24A

Block Diagram

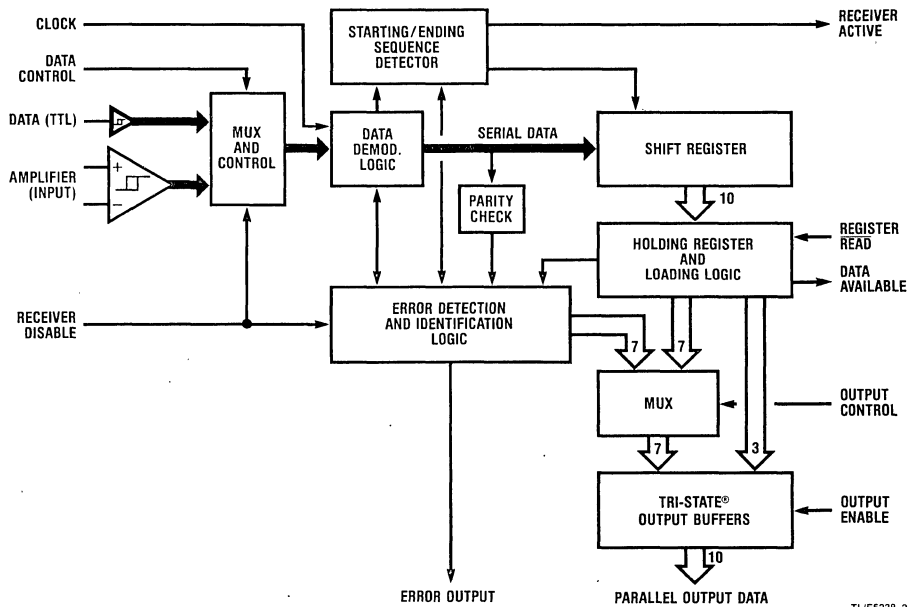


FIGURE 2. DP8341 Serial Bi-Phase Receiver/Decoder Block Diagram

Block Diagram Functional Description

Figure 2 is a block diagram of the DP8341. This chip is essentially a serial in/parallel out shift register. However, the serial input data must conform to a very specific format (see Figures 3-5). The message will not be recognized unless the format of the starting sequence is correct. Deviations from the format in the data, sync bit, parity or ending sequence will cause an error to be detected, terminating the message.

Data enters the receiver through the differential input amplifier or the TTL Data input. The differential amplifier is a high sensitivity input which may be used by connecting it directly to a transformer coupled coax line, or other transmission medium. The TTL Data input provides 400 mV of hysteresis and recognizes TTL logic levels. The data then enters the demodulation block.

The data demodulation block samples the data at eight (8) times the data rate and provides signals for detecting the starting sequence, ending sequence, and errors. Detection of the starting sequence sets the Receiver Active output high and enables the input shift register.

As the ten bits of data are shifted into the shift register, the receiver will verify that even parity is maintained on the data bits and the sync bit. After one complete data byte is received, the contents of the input shift register is parallel loaded to the holding register, assuming the holding register is empty, and the Data Available output is set. If the holding register is full, this load will be delayed until that register has been read. If another data byte is received when the shift register and the holding

register are full a Data Overflow Error will be detected, terminating the message. Data is read from the holding register through the TRI-STATE Output Buffers. The Output Enable input is the TRI-STATE control for these outputs and the Register Read input signals the receiver that the read has been completed.

When the receiver detects an ending sequence the Receiver Active output will be reset to a logic "0" indicating the message has been terminated. A message will also terminate when an error is detected. The Receiver Active output used in conjunction with the Error output allows quick response to the transmitting unit when an error free message has been received.

The Error Detection and Identification block insures that valid data reaches the outputs of the receiver. Detection of an error sets the Error output to a logic "1" and resets the Receiver Active output to a logic "0" terminating the message. The error type may be read from the data bus outputs by setting the Output Control input to logic "0" and enabling the TRI-STATE outputs. The data bit outputs have assigned error definitions (see error code definition table). The Error output will return to a logic "0" when the next starting sequence is received, or when the error is read (Output Control to logic "0" and a Register Read performed).

The Receiver Disable input is used to disable both the amplifier and TTL Data receiver inputs. It will typically be connected directly to the Transmitter Active output of the DP8340 transmitter circuit (see Figure 12).

Detailed Functional Pin Description

Receiver Disable

This input is used to disable the receiver's data inputs. The Receiver Disable input will typically be connected to the Transmitter Active output of the DP8340. However, at the system controller it is necessary for both the transmitter and receiver to be active at the same time in the loop-back check condition. This variation can be accomplished with the addition of minimal external logic.

Truth Table

Receiver Disable	Data Inputs
Logic "0"	Active
Logic "1"	Disabled

Amplifier Inputs

The receiver has a differential input amplifier which may be directly connected to the transformer coupled coax line. The amplifier may also be connected to a differential type TTL line. The amplifier has 20mV of hysteresis.

Data Input

This input can be used either as an alternate data input or as a power-up check input. If the system designer prefers to use his own amplifier, instead of the one provided on the receiver, then this TTL input may be used. Using this pin as an alternate data input allows self-test of the peripheral system without disturbing the transmission line.

Data Control

This input is the control pin that selects which of the inputs are used for data entry to the receiver.

Truth Table

Data Control	Data Input To
Logic "0"	Data Input
Logic "1"	Amplifier Inputs

Note: This input is also used for testing. When the input voltage is raised to 7.5V the chip resets.

Clock Input

This input is the internal clock of the receiver. It must be set at eight (8) times the line data bit rate. For the IBM 3270 Standard, this frequency is 18.87 MHz or a data bit rate of 2.358 MHz. The crystal-controlled oscillator pro-

vided in the DP8340 transmitter also operates at this frequency. The Clock Output of the transmitter is designed to directly drive the receiver's Clock Input. In addition, the receiver is designed to operate correctly to a data bit rate of 3.5 MHz.

Receiver Active

The purpose of this output is to inform the external system when the DP8341 is in the process of receiving a message. This output will transition to a logic "1" state after the receipt of a valid starting sequence and transition to logic "0" when a valid ending sequence is received or an error is detected. This output combined with the Error output will inform the operating system of the end of an error free data transmission.

Error

The Error output transitions to a logic "1" when an error is detected. Detection of an error causes the Receiver Active and the Data Available outputs to transition to a logic "0". The Error output returns to a logic "0" after the error register has been read or when the next starting sequence is detected.

Register Read

The Register Read input when driven to the logic "0" state signals the receiver that data in the holding register is being read by the external operating system. The data present in the holding register will continue to remain valid until the Register Read input returns to the logic "1" condition. At this time, if an additional byte is present in the input shift register it will be transferred to the holding register, otherwise the data will remain valid in the holding register. The Data Available output will be in the logic "0" state for a short interval while a new byte is transferred to the holding register after a register read.

Data Available

This output indicates the existence of a data byte within the output holding register. It may also indicate the presence of a data byte in both the holding register and the input shift register. This output will transition to the logic "1" state as soon as data is available and return to the logic "0" state after each data byte has been read. However, even after the last data byte has been read and the Data Available output has assumed the logic "0" state, the last data byte read from the holding register will remain until new data has been received.

Output Control

The Output Control input determines the type of information appearing at the data outputs. In the logic "1" state data will appear, in the logic "0" state error codes are present.

Truth Table

Output Control	Data Outputs
Logic "0"	Error Codes
Logic "1"	Data

Output Enable

The Output Enable input controls the state of the TRI-STATE Data outputs.

Truth Table

Output Enable	TRI-STATE® Data Outputs
Logic "0"	Disabled
Logic "1"	Active

Data Outputs

The DP8341 has a ten (10) bit TRI-STATE data bus. Seven bits are multiplexed with error bits. The error bits are de-

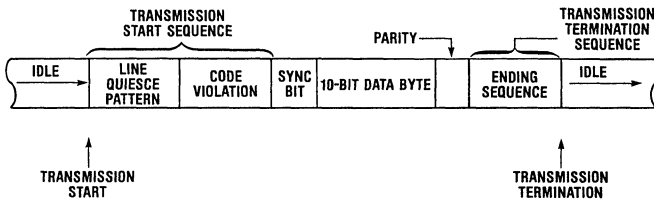
finied in the table below. The Output Control input is the multiplexer control for the Data/Error bits.

Error Code Definition

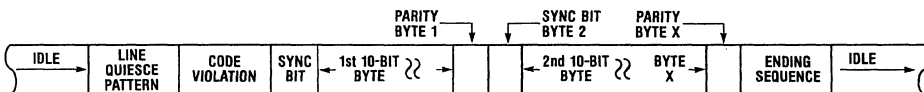
Data Bit	Error Type
DO2	Data Overflow (Byte not removed from holding register when it and the input shift register are both full and new data is received)
DO3	Parity Error (Odd parity detected)
DO4	Transmit Check conditions (existence of errors on any or all of the following data bits: DO3, DO5, and DO6)
DO5	An invalid ending sequence
DO6	Loss of mid-bit transition detected at other than normal ending sequence time
DO7	New starting sequence detected before data byte in holding register has been read
DO8	Receiver disabled during receiver active mode

Message Format

Single Byte Transmission



Multi-Byte Transmission



TL/F5238-3

FIGURE 3. IBM 3270 Message Format

Message Format

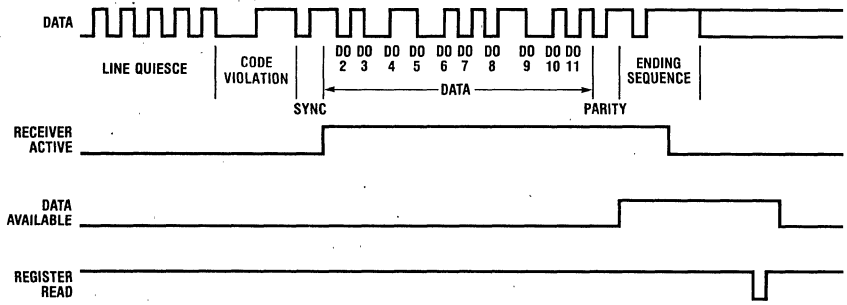


FIGURE 4A. Single Byte Message

TUF5238-4

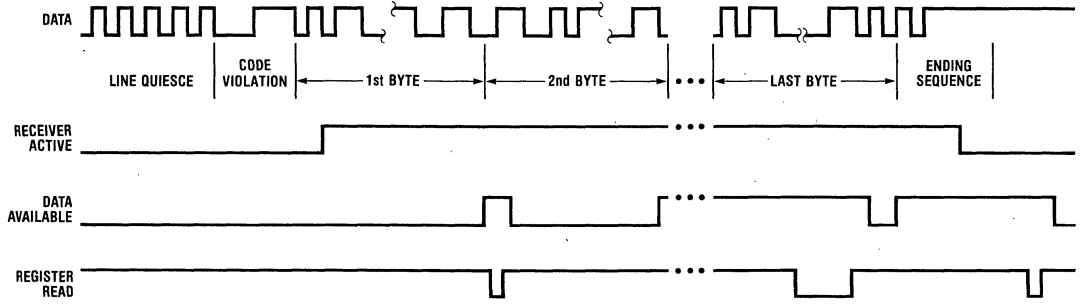


FIGURE 4B. Multi-Byte Message

TUF5238-5

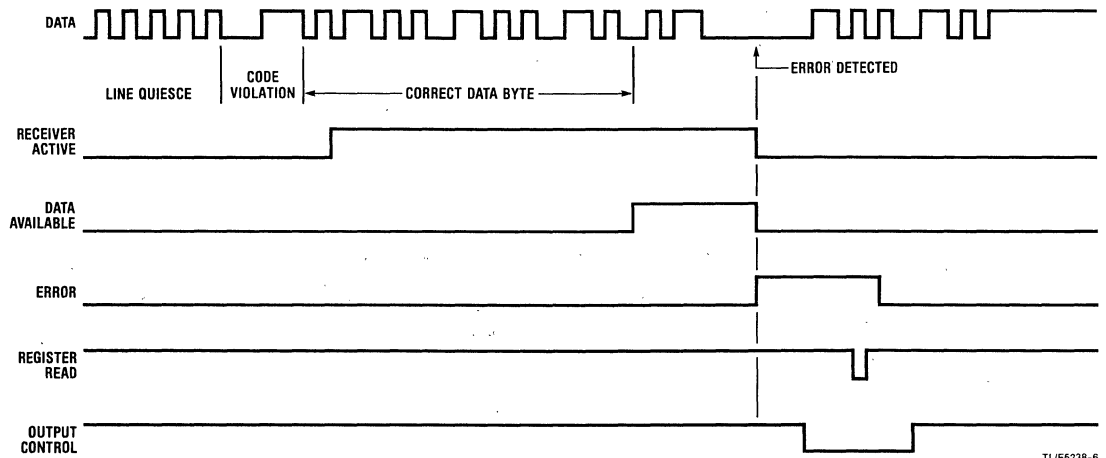


FIGURE 5. Message with Error

TUF5238-6

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7V
Input Voltage	+5.5V
Output Voltage	5.25V
Storage Temperature Range	-65°C to 150°C
Lead Temperature (soldering, 10 seconds)	300°C
Maximum Power Dissipation* at 25°C	
Cavity Package	2040 mW
Molded Package	2237 mW

*Derate cavity package 13.6 mW/°C above 25°C; derate molded package 17.9 mW/°C above 25°C.

Operating Conditions

Supply Voltage, (V_{CC})	Min. 4.75	Max. 5.25	Units V
Ambient Temperature, (T_A)	0	+70	°C

Electrical Characteristics (Notes 2, 3, and 5)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	Input High Level		2.0			V
V_{IL}	Input Low Level				0.8	V
$V_{IH}-V_{IL}$	Data Input Hysteresis (TTL, Pin 4)		0.2	0.4		V
V_{CLAMP}	Input Clamp Voltage	$I_{IN} = -12\text{ mA}$		-0.8	-1.2	V
I_{IH}	Logic "1" Input Current	$V_{CC} = 5.25\text{ V}, V_{IN} = 5.25\text{ V}$		2	40	μA
I_{IL}	Logic "0" Input Current	$V_{CC} = 5.25\text{ V}, V_{IN} = 0.5\text{ V}$		-20	-250	μA
V_{OH}	Logic "1" Output Voltage	$I_{OH} = -100\ \mu\text{A}$	3.2	3.9		V
		$I_{OH} = -1\ \text{mA}$	2.5	3.2		V
V_{OL}	Logic "0" Output Voltage	$I_{OL} = 5\ \text{mA}$		0.35	0.5	V
I_{OS}	Output Short Circuit Current	$V_{CC} = 5\text{ V}, V_{OUT} = 0\text{ V}$ (See Note 4)	-10	-20	-100	mA
I_{OZ}	TRI-STATE® Output Current	$V_{CC} = 5.25\text{ V}, V_O = 2.5\text{ V}$	-40	1	+40	μA
		$V_{CC} = 5.25\text{ V}, V_O = 0.5\text{ V}$	-40	-5	+40	μA
A_{HYS}	Amplifier Input Hysteresis		5	20	30	mV
I_{CC}	Power Supply Current	$V_{CC} = 5.25\text{ V}$		160	250	mA

Timing Characteristics (Notes 2, 6, 7, and 8)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
T_{D1}	Output Data to Data Available Positive Edge		5	20	40	ns
T_{D2}	Register Read Positive Edge to Data Available Negative Edge		10	25	45	ns
T_{D3}	Error Positive Edge to Data Available Negative Edge		10	30	50	ns
T_{D4}	Error Positive Edge to Receiver Active Negative Edge		5	20	40	ns
T_{D5}	Register Read Positive Edge to Error Negative Edge		20	45	75	ns
T_{D6}	Delay from Output Control to Error Bits from Data Bits		5	20	50	ns
T_{D7}	Delay from Output Control to Data Bits from Error Bits		5	20	50	ns
T_{D8}	First Sync Bit Positive Edge to Receiver Active Positive Edge			3.5•T +70		ns
T_{D9}	Receiver Active Positive Edge to First Data Available Positive Edge			92•T		ns
T_{D10}	Negative Edge of Ending Sequence to Receiver Active Negative Edge			11.5•T +50		ns
T_{D11}	Data Control Set-up Multiplexer Time Prior to Receiving Data through Selected Input		40	30		ns

Timing Characteristics (Cont'd) (Notes 2, 6, 7, and 8)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
T_{PW1}	Register Read (Data) Pulse Width		40	30		ns
T_{PW2}	Register Read (Error) Pulse Width		40	30		ns
T_{PW3}	Data Available Logic "0" State between Data Bytes		25	45		ns
T_S	Output Control Set-up Time Prior to Register Read Negative Edge		0	-5		ns
T_H	Output Control Hold Time After the Register Read Positive Edge		0	-5		ns
T_{ZE}	Delay from Output Enable to Logic "1" or Logic "0" from High Impedance State	Load Circuit 2		25	35	ns
T_{EZ}	Delay from Output Enable to High Impedance State from Logic "1" or Logic "0"	Load Circuit 2		25	35	ns
F_{MAX}	Data Bit Frequency (Clock Input must be 8x the Data Bit Frequency)		DC		3.5	Mbits/s

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min./max. limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0\text{V}$.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max. or min. are so classified on absolute value basis.

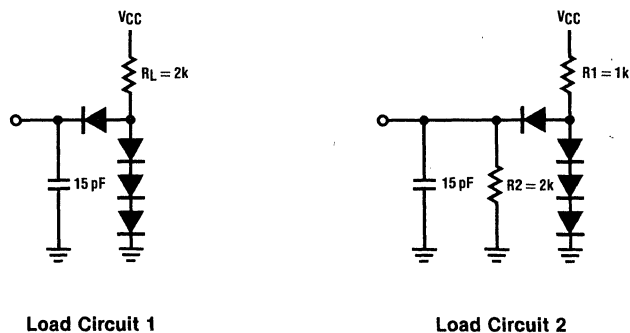
Note 4: Only one output at a time should be shorted.

Note 5: Input characteristics do not apply to amplifier inputs (pins 2 & 3).

Note 6: Unless otherwise specified, all AC measurements are referenced to the 1.5V level of the input to the 1.5V level of the output and load circuit 1 is used.

Note 7: AC tests are done with input pulses supplied by generators having the following characteristics: $Z_{OUT} = 50\Omega$ and $T_r \leq 5\text{ns}$, $T_f \leq 5\text{ns}$.

Note 8: $T = 1/(\text{clock input frequency})$, units for "T" should be ns.



TJF5238-7

FIGURE 6. Test Load Circuits

Timing Waveforms

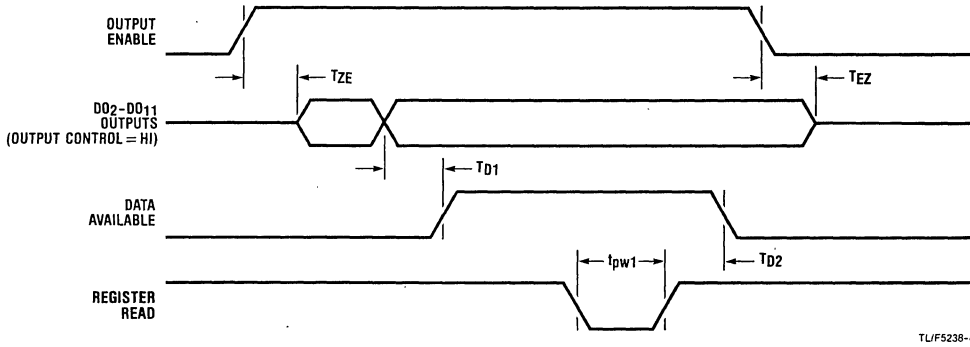


FIGURE 7. Data Sequence Timing

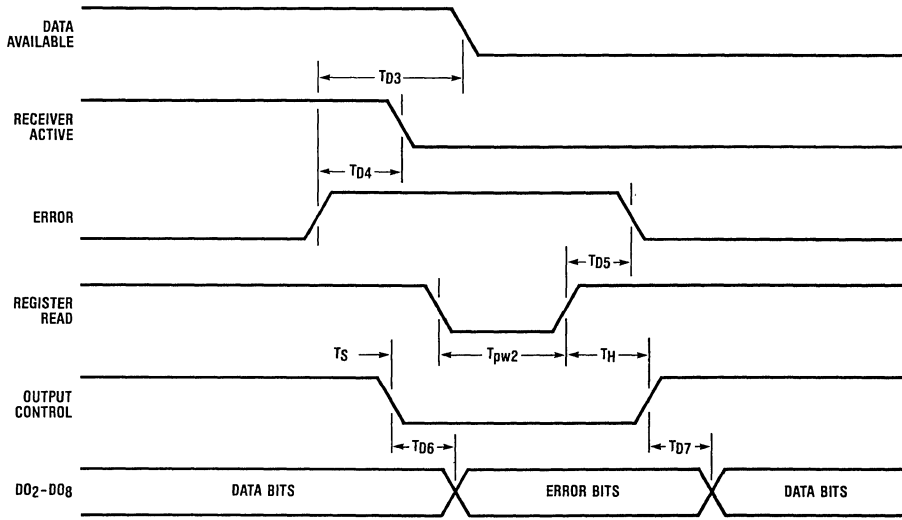


FIGURE 8. Error Sequence Timing

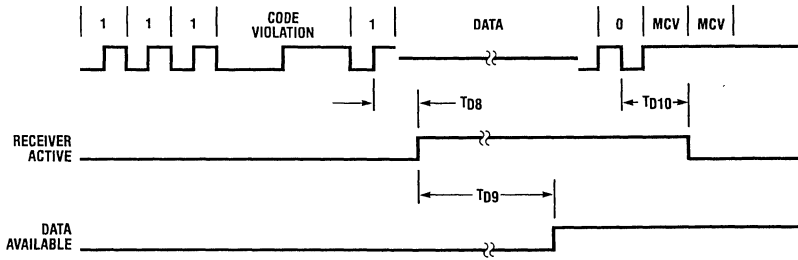
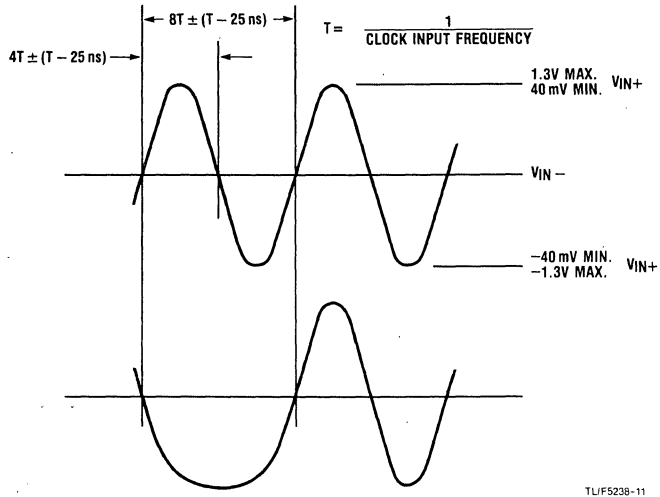


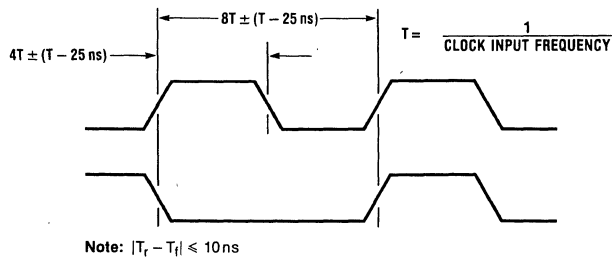
FIGURE 9. Message Timing

Timing Waveforms (Continued)



TLF5238-11

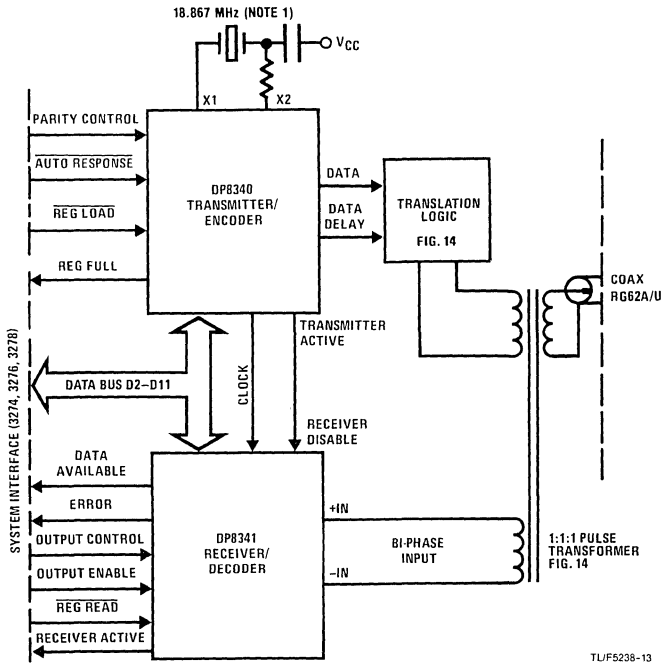
FIGURE 10. Data Waveform Constraints: Amplifier Inputs



TLF5238-12

FIGURE 11. Data Waveform Constraints: Data Input (TTL)

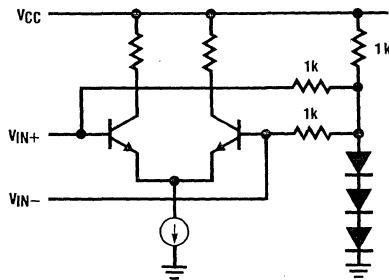
Typical Applications



TU/F5238-13

Note 1: Crystal manufacturer Midland Ross Corp.
NEL Unit Part No. NE18A @ 18.867MHz

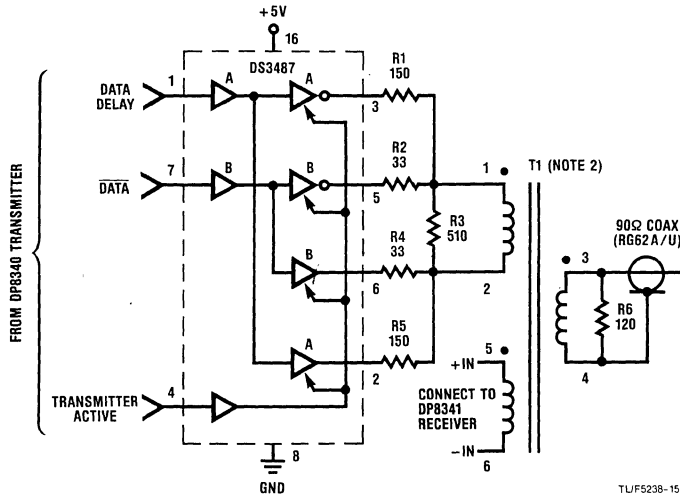
FIGURE 12. Typical Application for IBM 3270 Interface



TU/F5238-14

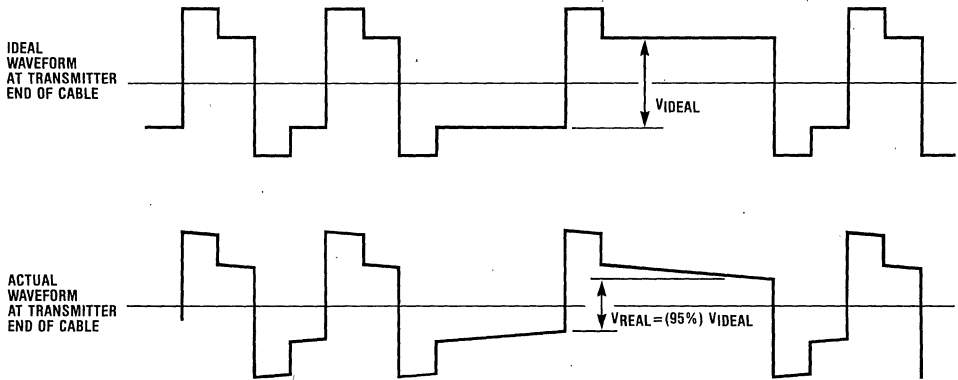
FIGURE 13. Equivalent Circuit for DP8341 Input Amplifier

Typical Applications (Continued)



- Notes: 1) Resistance values are in ohms, ±5%, ¼ W
 2) T1 is a 1:1:1 pulse transformer, L_{MIN} = 500µH for 18MHz system clock
 Pulse Engineering Part No. 5762
 Technitrol Part No. 11LHA or equivalent transformers

FIGURE 14. Translation Logic



* TO MAINTAIN LOSS AT 95% OF IDEAL SIGNAL, SELECT TRANSFORMER INDUCTANCE SUCH THAT:

$$L(\text{MIN}) = \frac{10,000}{f_{\text{CLK}}} \quad f_{\text{CLK}} = \text{SYSTEM CLOCK FREQUENCY (e.g., 18.87 MHz)}$$

EXAMPLE:

$$L = \frac{10,000}{18.87 \times 10^6} \rightarrow L(\text{MIN}) = 530 \mu\text{H}$$

- Notes: 1) Less inductance will cause greater amplitude attenuation
 2) Greater inductance may decrease signal rise time slightly and increase ringing, but these effects are generally negligible.

TUF5238-16

FIGURE 15. Transformer Selection

DP8342 High-Speed Serial Transmitter/Encoder

General Description

The DP8342 generates a complete encoding of parallel data for high speed serial transmission. It generates a five bit starting sequence, three bit code violation, followed by a syn bit and eight bit per byte of data plus a parity bit. A three-bit ending code signals the termination of the transmission. The DP8342 adapts to generalized high speed serial data transmission as well as the coax lines at a maximum data rate of 3.5MHz.

The DP8342 and its complementary chip, the DP8343 (receiver/decoder) have been designed to provide maximum flexibility in system designs. The separation of the transmitter/receiver functions provides convenient addition of more receivers at one end of a bi-phase line without the need of unused transmitters. This is specifically advantageous in control units where typical bi-phase data is multiplexed over many bi-phase lines and the number of receivers generally exceeds the number of transmitters.

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Features

- Eight bits per data byte transmission
- Single-byte or multi-byte transmission
- Internal parity generation (even or odd)
- Internal crystal controlled oscillator used for the generation of all required chip timing frequencies
- Clock output directly drives receiver (DP8343) clock input
- Input data holding register
- Automatic clear status response feature
- Line drivers at data outputs provide easy interface to bi-phase coax line or general transmission media
- <2ns driver output skew
- Bipolar technology provides TTL input/output compatibility
- Data outputs power up/down glitch free
- Internal power up clear and reset
- Single +5V power supply

Connection Diagram

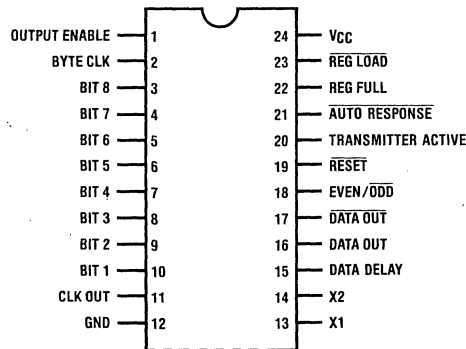


FIGURE 1.

Order Number DP8342J or DP8342N
See NS Package J24A or N24A

Block Diagram

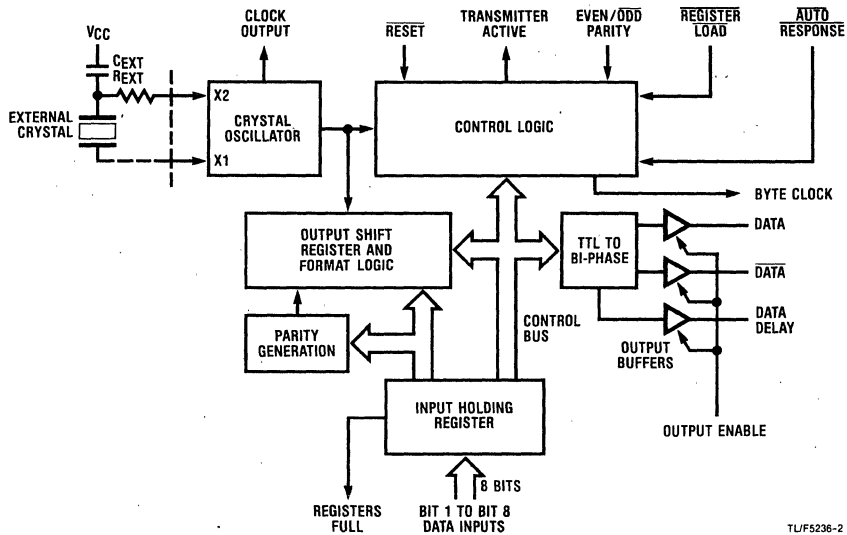


FIGURE 2.

Functional Description

Figure 2 is a block diagram of the DP8342 Bi-Phase Transmitter/Encoder. The transmitter/encoder contains a crystal oscillator whose input is a crystal with a frequency eight (8) times the data rate. A Clock Output is provided to drive the DP8342 receiver/decoder Clock Input and other system components at the oscillator frequency. Additionally, the oscillator drives the control logic and output shift register/format logic blocks.

Data is parallel loaded from the system data bus to the transmitter/encoder's input holding register. This data is in turn loaded by the transmitter/encoder to its output shift register if this register was empty at the time of the load. During this load, message formatting and parity are generated. The formatted message is then shifted out at the bit rate frequency to the TTL to Bi-Phase block which generates the proper data bit formatting. The data outputs, DATA, DATA, and DATA DELAY provide for flexible interface to the transmission medium with little or no external components.

The control Logic block interfaces to all blocks to insure proper chip operation and sequencing. It controls the type of parity generation through the Even/Odd Parity input. An additional feature provided by the transmitter/

encoder is the Reset and Output-TRI-STATE® capability. Another feature of the DP8342 is the Byte Clock output which keeps track of the number of bytes transferred.

The transmitter/encoder is also capable of internal TT/AR (Transmission Turnaround/Auto Response). When the Auto-Response (AR) input is forced to the logic "0" state, the transmitter/encoder responds with clean status (all zeros on data bits).

Operation of the transmitter/encoder is automatic. After the first data byte is loaded, the Transmitter Active output is set and the transmitter/encoder immediately formats the input data and serially shifts it out its data outputs. If the message is a multi-byte message, the internal format logic will modify the message data format for multibyte as long as the next byte is loaded to the input holding register before the last data bit of the previous data byte is transferred out of the internal output shift register. After all data is shifted out of the transmitter/encoder the Transmitter Active output will return to the inactive state.

Detailed Pin/Functional Description

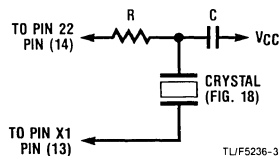
Crystal Inputs X1 and X2

The oscillator is controlled by an external, parallel resonant crystal connected between the X1 and X2 pins. Normally, a fundamental mode crystal is used to determine the operating frequency of the oscillator; however, overtone mode crystals may be used.

Crystal Specifications (Parallel Resonant)

Type	<20MHz AT-cut or >20MHz BT-cut
Tolerance	0.005% at 25°C
Stability	0.01% from 0°C to +70°C
Resonance	Fundamental (Parallel)
Maximum Series Resistance	Dependent on Frequency (For 20MHz, 50Ω)
Load Capacitance	15pF

Connection Diagram



FREQ	R	C
<20 MHz	500 Ω	30 pF
>20 MHz	120 Ω	15 pF

If the DP8342 transmitter is clocked by a system clock (crystal oscillator not used), pin 13 (X1 input) should be clocked directly using a Schottky series (74S) circuit. Pin 14 (X2 input) may be left open. The clocking frequency must be set at eight times the data bit rate. Maximum input frequency is 28 MHz.

Clock Output

The Clock Output is a buffered output derived directly from the crystal oscillator block and clocks at the oscillator frequency. It is designed to directly drive the DP8343 receiver/decoder Clock Input as well as other system components.

Registers Full

This output is used as a flag by the external operating system. A logic "1" (active state) on this output indicates that both the internal output shift register and the input holding register contain active data. No additional data should be loaded until this output returns to the logic "0" state (inactive state).

Transmitter Active

This output will be in the logic "1" state while the transmitter/encoder is about to transmit or in the process of transmitting data. Otherwise, it will assume the logic "0" state indicating no data presently in either the input holding or output shift registers.

Register Load

The Register Load input is used to load data from the Data Inputs to the input holding register. The loading function is level sensitive, the data present during the logic "0" state of this input is loaded, and the input data must be valid before the logic "0" to logic "1" transition. It is after this transition that the transmitter/encoder begins formatting of data for serial transmission.

Auto Response (TTIAR)

This input provides for automatic clear data transmission (all bits in logic "0") without the need of loading all zero's. When a logic "0" is forced on this input the transmitter/encoder immediately responds with transmission of "clean status". When this input is in the logic "1" state the transmitter/encoder transmits data entered on the Data Inputs.

Even/Odd Parity

This input sets the internal logic of the DP8342 transmitter/encoder to generate either even or odd parity for the data byte in the bit 10 position. When this pin is in the logic "0" state odd parity is generated. In the logic "1" state even parity is generated. This feature is useful when the control unit is performing a loop back check and at the same time the controller wishes to verify proper data transmission with its receiver/decoder.

Serial Outputs — DATA, $\overline{\text{DATA}}$, and DATA DELAY

These three output pins provide for convenient application of data to the Bi-Phase transmission line. The Data outputs are a direct bit representation of the Bi-Phase data while the Data Delay output provides the necessary increment to clearly define the four (4) DC levels of the pulse. The DATA and $\overline{\text{DATA}}$ outputs add flexibility to the DP8342 transmitter/encoder for use in high speed differential line driving applications. The typical DATA to $\overline{\text{DATA}}$ skew is 2ns.

RESET

When a logic "0" is forced on this input, all outputs except Clock Output are latched low.

Output Enable

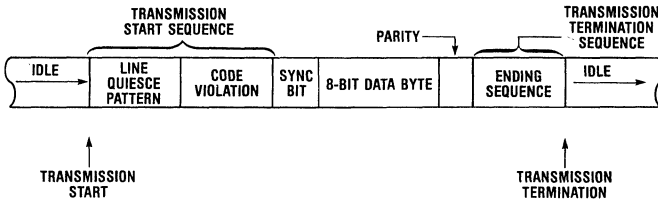
When a logic "0" is forced on this input the three serial data outputs are in the high impedance state.

Byte Clock

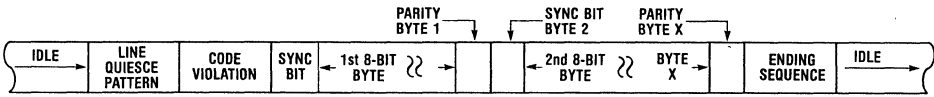
This pin registers a pulse at the end of each byte transmission. The number of pulses registered corresponds to the number of bytes transmitted.

Message Format

Single Byte Transmission



Multi-Byte Transmission



TU/F5236-4

FIGURE 3.

Functional Timing Waveforms

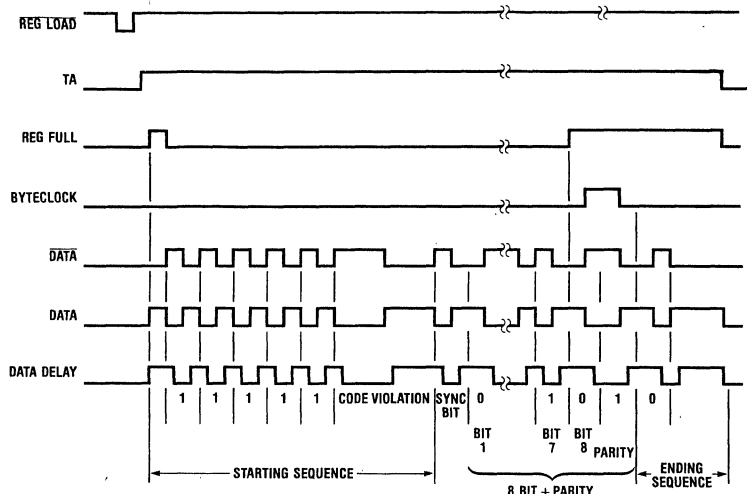


FIGURE 4. Overall Timing Waveforms for Single Byte

TU/F5236-5

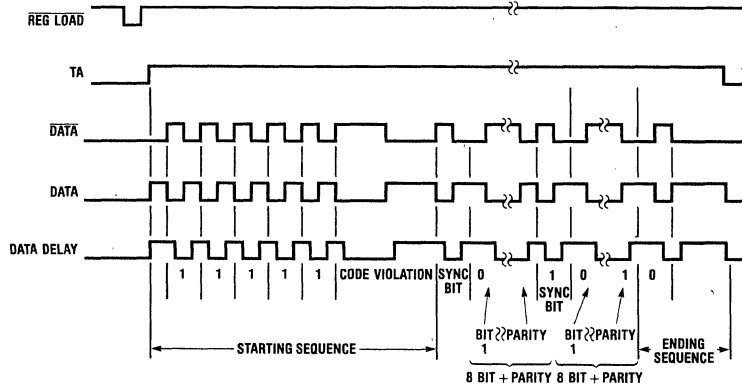


FIGURE 5. Overall Timing Waveforms for Multi-Byte

TU/F5236-6

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7V
Input Voltage	5.5V
Output Voltage	5.25V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (soldering, 10 seconds)	300°C
Maximum Power Dissipation* at 25°C	
Cavity Package	2237 mW
Molded Package	2500 mW

* Derate cavity package 14.9 mW/°C above 25°C; derate molded package 20 mW/°C above 25°C.

Operating Conditions

	Min.	Max.	Units
Supply Voltage, (V_{CC})	4.75	5.25	V
Ambient Temperature, T_A	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	Logic "1" Input Voltage (All Inputs Except X1 and X2)	$V_{CC} = 5V$	2.0			V
V_{IL}	Logic "0" Input Voltage (All Inputs Except X1 and X2)	$V_{CC} = 5V$			0.8	V
V_{CLAMP}	Input Clamp Voltage (All Inputs Except X1 and X2)	$I_{IN} = -12 mA$		-0.8	-1.2	V
I_{IH}	Logic "1" Input Current Register Load Input	$V_{CC} = 5.25V$ $V_{IN} = 5.25V$		0.3	120	μA
	All Others Except X1 and X2			0.1	40	μA
I_{IL}	Logic "0" Input Current Register Load Input	$V_{CC} = 5.25V$ $V_{IN} = 0.5V$		-15	-300	μA
	All Inputs Except X1 and X2			-5	-100	μA
V_{OH1}	Logic "1" All Outputs Except CLK OUT, DATA, \overline{DATA} , and DATA DELAY	$I_{OH} = -100 \mu A$ $V_{CC} = 4.75V$	3.2	3.9		V
		$I_{OH} = -1 mA$	2.5	3.4		V
V_{OH2}	Logic "1" for CKL OUT, DATA, \overline{DATA} and DATA DELAY Outputs	$V_{CC} = 4.75V$, $I_{OH} = -10 mA$	2.6	3.0		V
V_{OL1}	Logic "0" All Outputs Except CLK OUT, DATA, \overline{DATA} , and DATA DELAY	$V_{CC} = 4.75V$ $I_{OL} = 5 mA$		0.35	0.5	V
V_{OL2}	Logic "0" for CLK OUT, DATA, \overline{DATA} and DATA DELAY Outputs	$V_{CC} = 4.75V$ $I_{OL} = 20 mA$		0.4	0.6	V
I_{OS1}	Output Short Circuit Current for All Except CLK OUT, DATA, \overline{DATA} , and DATA DELAY Outputs	Note 5 $V_{OUT} = 0V$	-10	-30	-100	mA
I_{OS2}	Output Short Circuit Current DATA, \overline{DATA} , and DATA DELAY Outputs	Note 5 $V_{OUT} = 0V$	-50	-140	-250	mA
I_{OS3}	Output Short Circuit Current for CLK OUT	Note 5 $V_{OUT} = 0V$	-30	-90	-200	mA
I_{CC}	Power Supply Current	$V_{CC} = 5.25V$		170	250	mA

Timing Characteristics $V_{CC} = 5V \pm 5\%$, $T_A = 0^\circ C$ to $70^\circ C$, Oscillator Frequency = 28 MHz (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{pd1}	REG LOAD to Transmitter Active (T_A) Positive Edge	Load Circuit 1 Figure 6		60	90	ns
t_{pd2}	REG LOAD to Register Full; Positive Edge	Load Circuit 1 Figure 6		45	75	ns
t_{pd3}	T_A to Register Full; Negative Edge	Load Circuit 1 Figure 6		40	70	ns
t_{pd4}	Positive Edge of REG LOAD to Positive Edge of DATA	Load Circuit 2 Figure 9		50	80	ns
t_{pd5}	REG LOAD to DATA; Positive Edge	Load Circuit 2 Figure 9		280	380	ns
t_{pd6}	REG LOAD to DATA DELAY; Positive Edge	Load Circuit 2 Figure 9		150	240	ns
t_{pd7}	Positive Edge of \overline{DATA} to Negative Edge of DATA DELAY	Load Circuit 2 Figure 9		70	85	ns

Timing Characteristics (Continued) Oscillator Frequency = 28MHz (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{pd8}	Positive Edge of DATA DELAY to Negative Edge of DATA	Load Circuit 2 Figure 9		80	95	ns
t_{pd9} , t_{pd10}	Skew between DATA and $\overline{\text{DATA}}$	Load Circuit 2 Figure 9		2	6	ns
t_{pd11}	Negative Edge of Auto Response ($\overline{\text{AR}}$) to Positive Edge of TA	Load Circuit 1 Figure 10		70	100	ns
t_{pd12}	Maximum Time Delay to Load Second Byte After Positive Edge of REG FULL	Load Circuit 1 Figure 8, Note 7			$4 \times T - 50$	ns
t_{pd13}	X1 to CLK OUT; Positive Edge	Load Circuit 2 Figure 11		21	30	ns
t_{pd14}	X1 to CLK OUT; Negative Edge	Load Circuit 2 Figure 11		23	33	ns
t_{pd15}	Negative Edge of $\overline{\text{AR}}$ to Positive Edge of REG FULL	Load Circuit 1 Figure 10		45	75	ns
t_{pd16}	Skew between TA and REG FULL during Auto Response	Load Circuit 1 Figure 10		50	80	ns
t_{pd17}	REG LOAD to REG FULL; Positive Edge for Second Byte	Load Circuit 1 Figure 7		45	75	ns
t_{pd18}	REG FULL to BYTE CLK; Negative Edge	Load Circuit 1 Figure 7		60	90	ns
t_{pd19}	REG FULL to BYTE CLK; Positive Edge	Load Circuit 1 Figure 7		145	180	ns
t_{ZH}	Output Enable to DATA, $\overline{\text{DATA}}$, or DATA Delay outputs: HiZ to High	CL = 50pF Figures 17, 17		25	45	ns
t_{ZL}	Output Enable to DATA, $\overline{\text{DATA}}$, OR DATA Delay Outputs; HiZ to High	CL = 50pF Figures 16, 17		15	30	ns
t_{HZ}	Output Enable to DATA, $\overline{\text{DATA}}$, or DATA Delay Outputs; High to HiZ	CL = 15pF Figures 16, 17		65	100	ns
t_{LZ}	Output Enable to DATA, $\overline{\text{DATA}}$, or DATA Delay Outputs; Low to HiZ	CL = 15pF Figures 16, 17		45	70	ns
t_{pw1}	REG LOAD Pulse Width	Figure 12	40			ns
t_{pw2}	First REG FULL Pulse Width (Note 6)	Load Circuit 1 Figure 7, Note 7		$8 \times T + 60$	$8 \times T + 100$	ns
t_{pw3}	REG FULL Pulse Width Prior to Ending Sequence (Note 6)	Load Circuit 1 Figure 7		$5 \times B$		ns
t_{pw4}	Pulse Width for Auto Response	Figure 10	40			ns
t_{pw5}	Pulse Width for BYTE CLK	Load Circuit 1 Figure 7, Note 7		$8 \times T + 30$	$8 \times T + 80$	ns
t_s	Data Setup Time prior to REG LOAD Positive Edge. Hold Time = 0ns	Figure 12		15	23	ns
t_{r1}	Rise Time for DATA, $\overline{\text{DATA}}$, and DATA DELAY Output Waveform	Load Circuit 2, Figure 13		7	13	ns
t_{f1}	Fall Time for DATA, $\overline{\text{DATA}}$, and DATA DELAY Output Waveform	Load Circuit 2, Figure 13		5	11	ns
t_{r2}	Rise Time for TA and REG FULL	Load Circuit 1 Figure 14		20	30	ns
t_{f2}	Fall Time for TA and REG FULL	Load Circuit 1 Figure 14		15	25	ns
f_{MAX}	Data Rate Frequency (Clock Input must be 8X this Frequency)		DC		3.5	Mbits/s
C_{IN}	Input Capacitance — Any Input	Note 4		5	15	pF

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min./max. limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0\text{V}$.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max. or min. are so classified on absolute basis.

Note 4: Input capacitance is guaranteed by periodic testing. $f_{TEST} = 10\text{kHz}$ at 300mV, $T_A = 25^\circ\text{C}$.

Note 5: Only one output should be shorted at a time.

Note 6: $T = 1/(\text{Oscillator Frequency})$. Unit for T should be in ns. $B = 8T$.

Note 7: Oscillator Frequency Dependent.

Timing Waveforms (Continued)

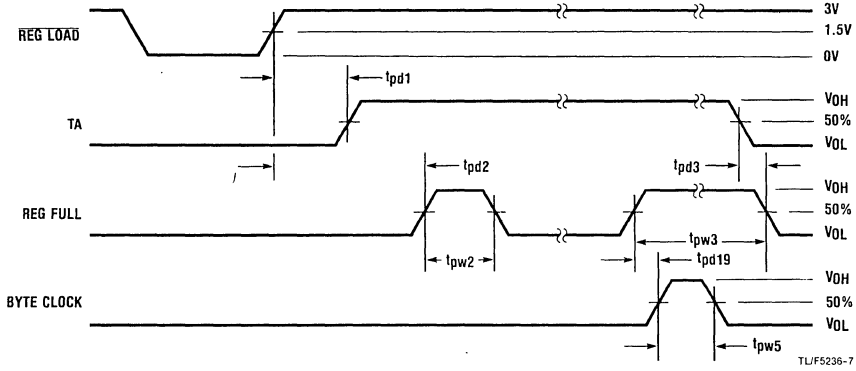


FIGURE 6. Single Byte Transfer

TU/F5236-7

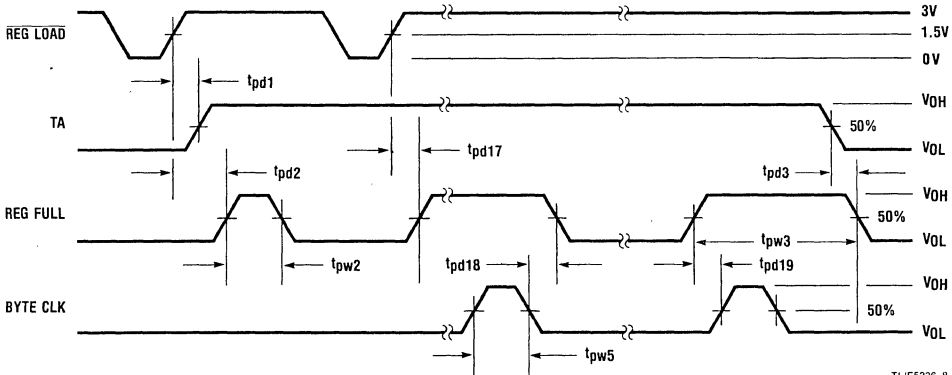


FIGURE 7. Two-Byte Transfer

TU/F5236-8

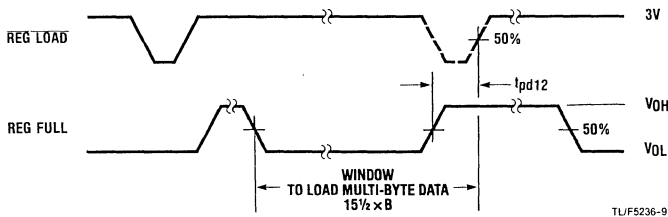


FIGURE 8. Maximum Window to Load Multi-Byte Data

TU/F5236-9

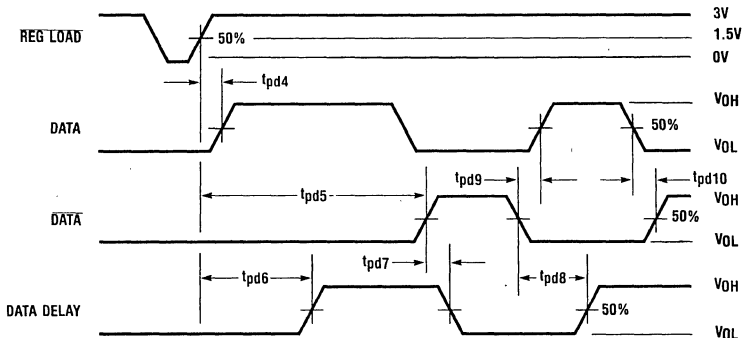


FIGURE 9. Three Serial Outputs

TU/F5236-10

Timing Waveforms (Continued)

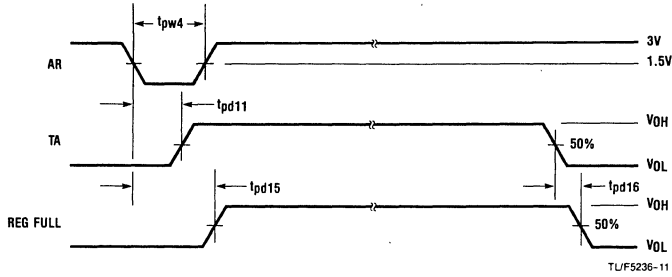


FIGURE 10. Auto-Response

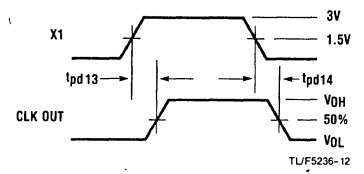


FIGURE 11. Clock Pulse

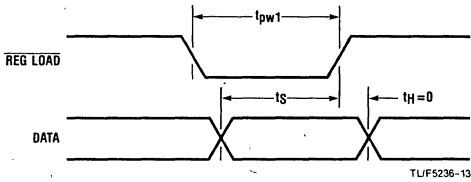


FIGURE 12. REG LOAD

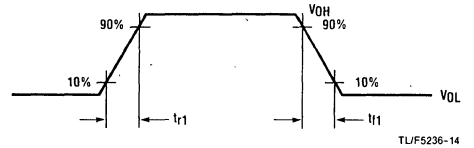


FIGURE 13. Output Waveform for DATA, DATA DELAY (Load Circuit 2)

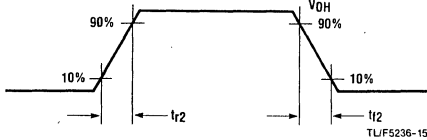
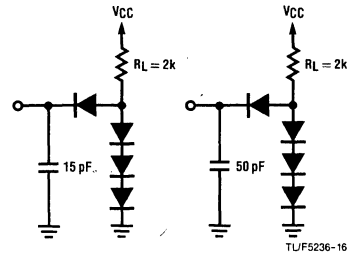


FIGURE 14. Rise and Fall Time Measurement for TA and REG FULL



Load Circuit 1 Load Circuit 2

FIGURE 15. Test Load Circuits

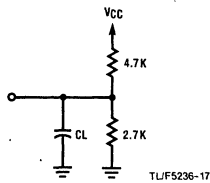


FIGURE 16. Load Circuit for Output TRI-STATE Test

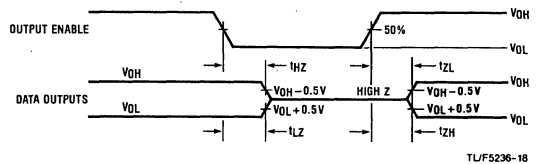
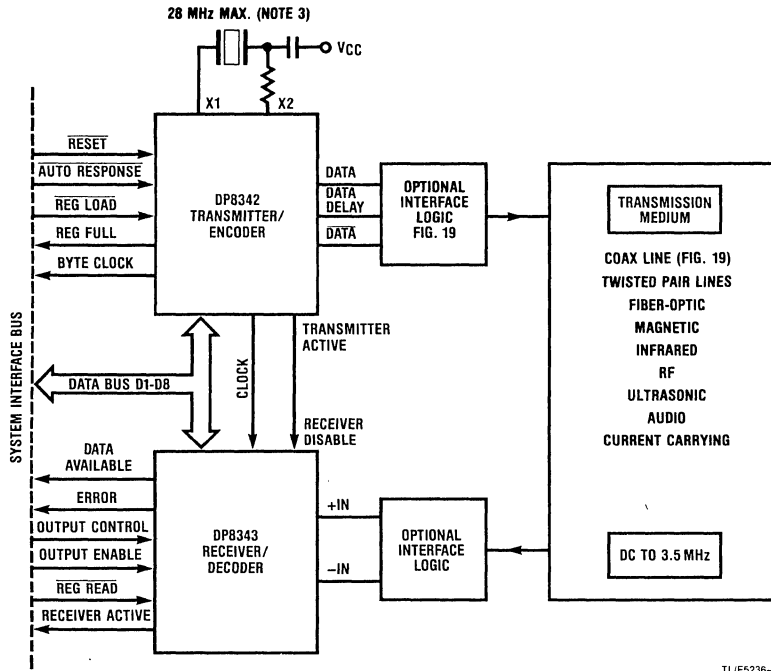


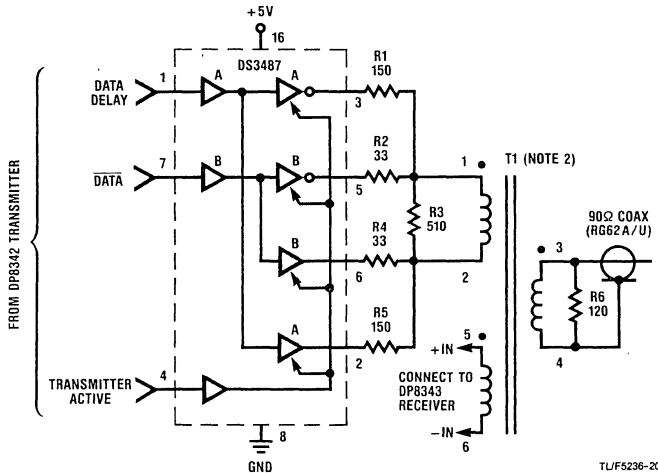
FIGURE 17. TRI-STATE Test

Typical Applications



TU/F5236-19

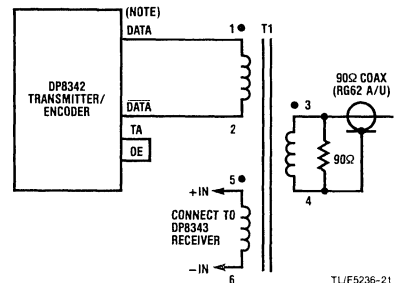
FIGURE 18.



TU/F5236-20

- Notes: 1) Resistance values are in ohms, $\pm 5\%$, $\frac{1}{4}$ W
 2) T1 is a 1:1:1 pulse transformer, $L = 500\mu\text{H}$ for 18 to 28MHz system clock. Pulse Engineering Part No. 5762 Technitrol Part No. 11LHA or equivalent transformer
 3) Crystal manufacturer Midland Ross Corp. NEL Unit Part No. NE-18A @ 28MHz.

FIGURE 19. Interface Logic for a Coax Transmission Line



TU/F5236-21

Note: Data rates up to 3.5Mbps/s at 5000ft still apply.

FIGURE 20. Direct Interface for a Coax Transmission Line (Non-IBM Voltage Levels)

DP8343 High-Speed Serial Receiver/Decoder

General Description

The DP8343 provides complete decoding of data for high speed serial data communications. In specific, the DP8343 receiver recognizes Bi-Phase serial data sent from its complementary chip, the DP8342 transmitter, and converts it into eight (8) bits of parallel data. These devices are easily adapted to generalized high speed serial data transmission systems that operate at bit rates up to 3.5 MHz.

The DP8343 receiver and the DP8342 transmitter are designed to provide maximum flexibility in system designs. The separation of transmitter and receiver functions allows addition of more receivers at one end of the Bi-Phase line without the necessity of adding unused transmitters. This is advantageous in control units where the data is typically multiplexed over many lines and the number of receivers generally exceeds the number of transmitters. The separation of transmitter and receiver function provides an additional advantage in flexibility of data bus organization. The data bus outputs of the receiver are TRI-STATE®, thus enabling the bus configuration to be organized as either a common transmit/receive (bi-directional) bus or as separate transmit and receive busses for higher speed.

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Features

- DP8343 receives eight (8) bit data bytes
- Separate receiver and transmitter provide maximum system design flexibility
- Even parity detection
- High sensitivity input on receiver easily interfaces to coax line
- Standard TTL data input on receiver provides generalized transmission line interface and also provides hysteresis
- Data holding register
- Multi-byte or single byte transfers
- TRI-STATE receiver data outputs provide flexibility for common or separated transmit/receive data bus operation
- Data transmission error detection on receiver provides for both error detection and error type definition
- Bipolar technology provides TTL input/output compatibility with excellent drive characteristics
- Single +5V power supply operation

Connection Diagram

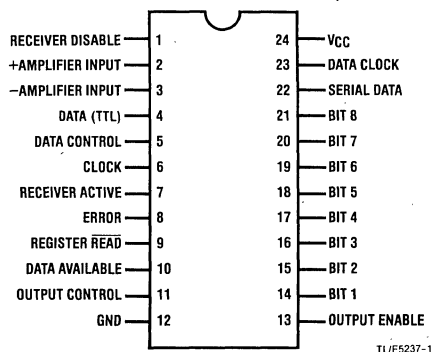
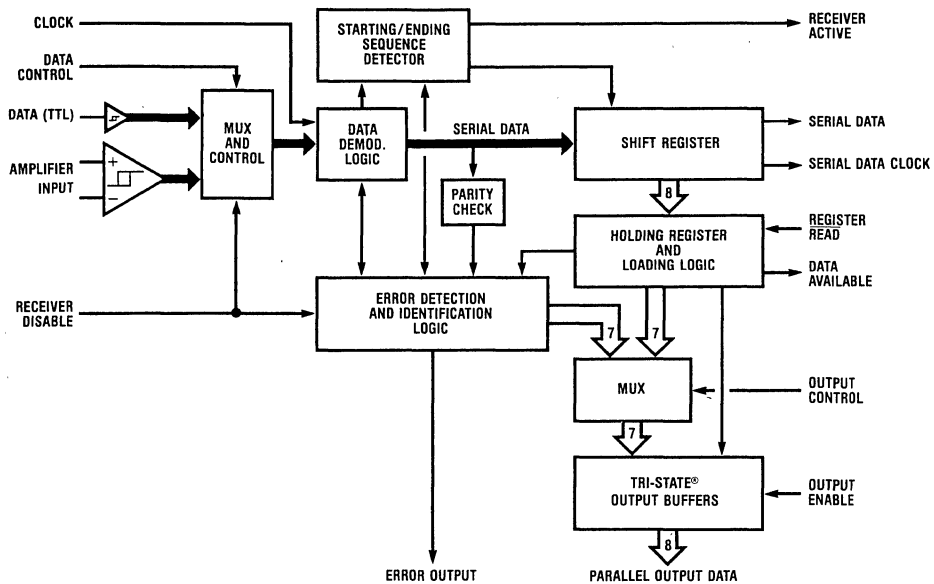


FIGURE 1.

Order Number DP8343J or DP8343N
See NS Package J24A or N24A

Block Diagram



TUF5237-2

FIGURE 2. DP8343 Bi-Phase Receiver

Block Diagram Functional Description

Figure 2 is a block diagram of the DP8343 receiver. This chip is essentially a serial in/parallel out shift register. However, the serial input data must conform to a very specific format (see Figures 3-6). The message will not be recognized unless the format of the starting sequence is correct. Deviations from the format in the data, sync bit, parity or ending sequence will cause an error to be detected, terminating the message.

Data enters the receiver through the differential input amplifier or the TTL Data input. The differential amplifier is a high sensitivity input which may be used by connecting it directly to a transformer coupled coax line, or other transmission medium. The TTL Data input provides 400 mV of hysteresis and recognizes TTL logic levels. The data then enters the demodulation block.

The data demodulation block samples the data at eight (8) times the data rate and provides signals for detecting the starting sequence, ending sequence, and errors. Detection of the starting sequence sets the Receiver Active output high and enables the input shift register.

As the eight bits of data are shifted into the shift register, the receiver will verify that even parity is maintained on the data bits and the sync bit. Serial Data and Serial Data Clock, the inputs to the shift register, are provided for use with external error detecting schemes. After one complete data byte is received, the contents of the input shift register is parallel loaded to the holding register, assuming the holding register is empty, and the Data Available output is set. If the holding register is full, this load will be delayed until that register has been read or

the start of another data byte is received, in which case a Data Overflow Error will be detected, terminating the message. Data is read from the holding register through the TRI-STATE Output Buffers. The Output Enable input is the TRI-STATE control for these outputs and the Register Read input signals the receiver that the read has been completed.

When the receiver detects an ending sequence the Receiver Active output will be reset to a logic "0" indicating the message has been terminated. A message will also terminate when an error is detected. The Receiver Active output used in conjunction with the Error output allows quick response to the transmitting unit when an error free message has been received.

The Error Detection and Identification block insures that valid data reaches the outputs of the receiver. Detection of an error sets the Error output to a logic "1" and resets the Receiver Active output to a logic "0" terminating the message. The error type may be read from the data bus outputs by setting the Output Control input to logic "0" and enabling the TRI-STATE outputs. The data bit outputs have assigned error definitions (see error code definition table). The Error output will return to a logic "0" when the next starting sequence is received, or when the error is read (Output Control to logic "0" and a Register Read performed).

The Receiver Disable input is used to disable both the amplifier and TTL Data receiver inputs. It will typically be connected directly to the Transmitter Active output of the DP8342 transmitter circuit.

Detailed Functional Pin Description

Receiver Disable

This input is used to disable the receiver's data inputs. The Receiver Disable input will typically be connected to the Transmitter Active output of the DP8342. However, at the system controller it may be necessary for both the transmitter and receiver to be active at the same time. This variation can be accomplished with the addition of minimal external logic.

Truth Table

Receiver Disable	Data Inputs
Logic "0"	Active
Logic "1"	Disabled

Amplifier Inputs

The receiver has a differential input amplifier which may be directly connected to the transformer coupled coax line. The amplifier may also be connected to a differential type TTL line. The amplifier has 20mV of hysteresis.

Data Input

This input can be used either as an alternate data input or as a power-up check input. If the system designer prefers to use his own amplifier, instead of the one provided on the receiver, then this TTL input may be used. Using this pin as an alternate data input allows self-test of the peripheral system without disturbing the transmission line.

Data Control

This input is the control pin that selects which of the inputs are used for data entry to the receiver.

Truth Table

Data Control	Data Input To
Logic "0"	Data Input
Logic "1"	Amplifier Inputs

Note: This input is also used for testing. When the input voltage is raised to 7.5V the chip resets.

Clock Input

This input is the internal clock of the receiver. It must be set at eight (8) times the line data bit rate. The crystal-controlled oscillator provided in the DP8342 transmitter also operates at this frequency. The Clock Output of the transmitter is designed to directly drive the receiver's Clock Input. In addition, the receiver is designed to operate correctly to a data bit rate of 3.5MHz.

Receiver Active

The purpose of this output is to inform the external system when the DP8343 is in the process of receiving a message. This output will transition to a logic "1" state after a receipt of a valid starting sequence and transition to logic "0" when a valid ending sequence is received or an error is detected. This output combined with the Error output will inform the operating system of the end of an error free data transmission.

Error

The Error output transitions to a logic "1" when an error is detected. Detection of an error causes the Receiver Active and the Data Available outputs to transition to a logic "0". The Error output returns to a logic "0" after the error register has been read or when the next starting sequence is detected.

Register Read

The Register Read input when driven to the logic "0" state signals the receiver that data in the holding register is being read by the external operating system. The data present in the holding register will continue to remain valid until the Register Read input returns to the logic "1" condition. At this time, if an additional byte is present in the input shift register it will be transferred to the holding register, otherwise the data will remain valid in the holding register. The Data Available output will be in the logic "0" state for a short interval while a new byte is transferred to the holding register after a register read.

Data Available

This output indicates the existence of a data byte within the output holding register. It may also indicate the presence of a data byte in both the holding register and the input shift register. This output will transition to the logic "1" state as soon as data is available and return to the logic "0" state after each data byte has been read. However, even after the last data byte has been read and the Data Available output has assumed the logic "0" state, the last data byte read from the holding register will remain until new data has been received.

Output Control

The Output Control input determines the type of information appearing at the data outputs. In the logic "1" state data will appear, in the logic "0" state error codes are present.

Truth Table

Output Control	Data Outputs
Logic "0"	Error Codes
Logic "1"	Data

Output Enable

The Output Enable input controls the state of the TRI-STATE Data outputs.

Truth Table

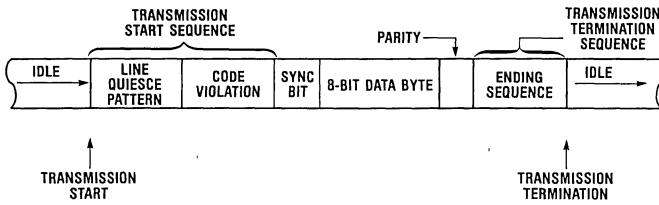
Output Enable	TRI-STATE Data Outputs
Logic "0"	Disabled
Logic "1"	Active

Data Outputs

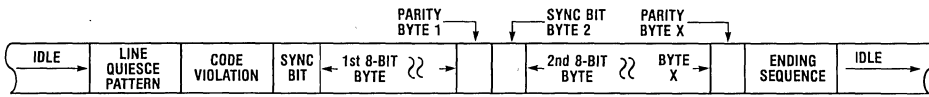
The DP8343 has an eight (8) bit TRI-STATE data bus. Seven bits are multiplexed with error bits. The error bits are defined in the table below. The Output Control input is the multiplexer control for the Data/Error bits.

Message Format

Single Byte Transmission

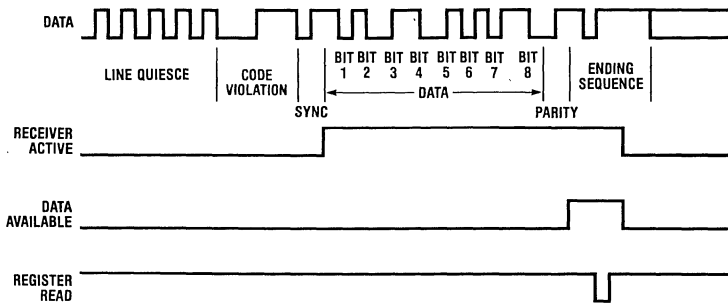


Multi-Byte Transmission



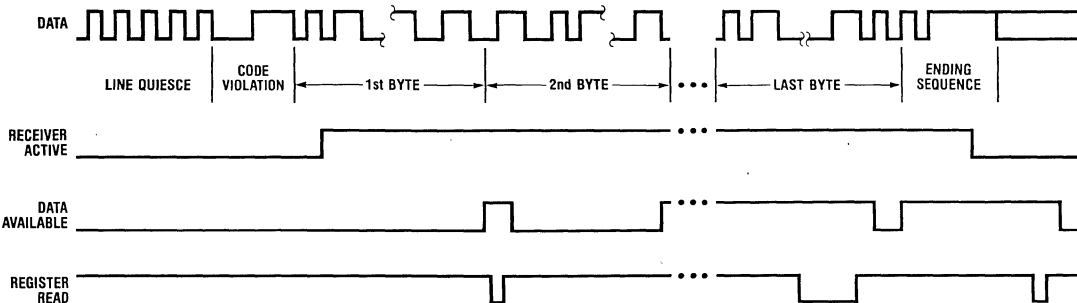
TUF5237-3

FIGURE 3.



TUF5237-4

FIGURE 4A. Single Byte (8-Bit) Message



TUF5237-5

FIGURE 4B. Multi-Byte Message

Error Code Definition

Data Bit DP8343	Error Type
Bit 1	Data Overflow (Byte not removed from holding register when it and the input shift register are both full and new data is received)
Bit 2	Parity Error (Odd parity detected)
Bit 3	Transmit Check conditions (existence of errors on any or all of the following data bits: Bit 2, Bit 4, and Bit 5)
Bit 4	An invalid ending sequence
Bit 5	Loss of mid-bit transition detected at other than normal ending sequence time
Bit 6	New starting sequence detected before data byte in holding register has been read
Bit 7	Receiver disabled during receiver active mode

Serial Data

The Serial Data output is the serial data coming into the input shift register.

Data Clock

The Data Clock output is the clock to the input shift register.

Message Format (Continued)

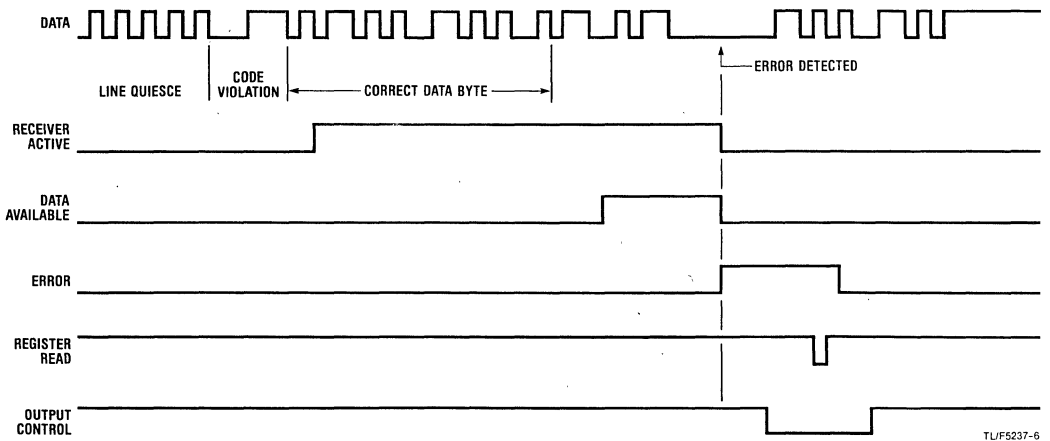


FIGURE 5. Message with Error

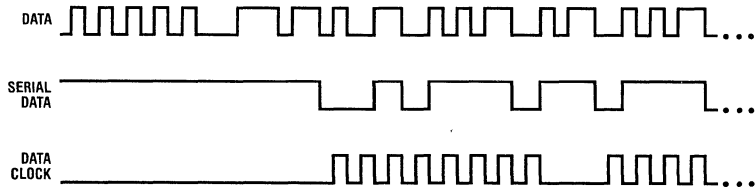


FIGURE 6. Data Clock and Serial Data

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Output Voltage	5.25V
Storage Temperature Range	-65°C to 150°C
Lead Temperature (soldering, 10 seconds)	300°C
Maximum Power Dissipation* at 25°C	
Cavity Package	2040 mW
Molded Package	2237 mW

* Derate cavity package 13.6 mW/°C above 25°C; derate molded package 17.9 mW/°C above 25°C.

Operating Conditions

	Min	Max	Units
Supply Voltage, (V_{CC})	4.75	5.25	V
Ambient Temperature, T_A	0	+70	°C

Electrical Characteristics (Notes 2, 3, and 5)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	Input High Level		2.0			V
V_{IL}	Input Low Level				0.8	V
$V_{IH}-V_{IL}$	Data Input Hysteresis (TTL, Pin 4)		0.2	0.4		V
V_{CLAMP}	Input Clamp Voltage	$I_{IN} = -12\text{ mA}$		-0.8	-1.2	V
I_{IH}	Logic "1" Input Current	$V_{CC} = 5.25\text{ V}, V_{IN} = 5.25\text{ V}$		2	40	μA
I_{IL}	Logic "0" Input Current	$V_{CC} = 5.25\text{ V}, V_{IN} = 0.5\text{ V}$		-20	-250	μA
V_{OH}	Logic "1" Output Voltage	$I_{OH} = -100\ \mu\text{A}$	3.2	3.9		V
		$I_{OH} = -1\ \text{mA}$	2.5	3.2		V
V_{OL}	Logic "0" Output Voltage	$I_{OL} = 5\ \text{mA}$		0.35	0.5	V
I_{OS}	Output Short Circuit Current	$V_{CC} = 5\text{ V}, V_{OUT} = 0\text{ V}$ (See Note 4)	-10	-20	-100	mA
I_{OZ}	TRI-STATE ² Output Current	$V_{CC} = 5.25\text{ V}, V_O = 2.5\text{ V}$	-40	1	+40	μA
		$V_{CC} = 5.25\text{ V}, V_O = 0.5\text{ V}$	-40	-5	+40	μA
A_{HYS}	Amplifier Input Hysteresis		5	20	30	mV
I_{CC}	Power Supply Current	$V_{CC} = 5.25\text{ V}$		160	250	mA

Timing Characteristics (Notes 2, 6, 7, and 8)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
T_{D1}	Output Data to Data Available Positive Edge		5	20	40	ns
T_{D2}	Register Read Positive Edge to Data Available Negative Edge		10	25	45	ns
T_{D3}	Error Positive Edge to Data Available Negative Edge		10	30	50	ns
T_{D4}	Error Positive Edge to Receiver Active Negative Edge		5	20	40	ns
T_{D5}	Register Read Positive Edge to Error Negative Edge		20	45	75	ns
T_{D6}	Delay from Output Control to Error Bits from Data Bits		5	20	50	ns
T_{D7}	Delay from Output Control to Data Bits from Error Bits		5	20	50	ns
T_{D8}	First Sync Bit Positive Edge to Receiver Active Positive Edge			$3.5 \cdot T$ +70		ns
T_{D9}	Receiver Active Positive Edge to First Data Available Positive Edge			$76 \cdot T$		ns
T_{D10}	Negative Edge of Ending Sequence to Receiver Active Negative Edge			$11.5 \cdot T$ +50		ns
T_{D11}	Data Control Set-up Multiplexer Time Prior to Receiving Data through Selected Input		40	30		ns
T_{D12}	Serial Data Set-Up Prior to Data Clock Positive Edge			$3 \cdot T$		ns

Timing Characteristics (Continued) (Notes 2, 6, 7, and 8)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
T _{PW1}	Register Read (Data) Pulse Width		40	30		ns
T _{PW2}	Register Read (Error) Pulse Width		40	30		ns
T _{PW3}	Data Available Logic "0" State between Data Bytes		25	45		ns
T _S	Output Control Set-up Time Prior to Register Read Negative Edge		0	-5		ns
T _H	Output Control Hold Time After the Register Read Positive Edge		0	-5		ns
T _{ZE}	Delay from Output Enable to Logic "1" or Logic "0" from High Impedance State	Load Circuit 2		25	35	ns
T _{EZ}	Delay from Output Enable to High Impedance State from Logic "1" or Logic "0"	Load Circuit 2		25	35	ns
F _{MAX}	Data Bit Frequency (Clock Input must be 8× the Data Bit Frequency)		DC		3.5	MBits/s

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min./max. limits apply across the 0°C to +70°C temperature range and the 4.75V to 5.25V power supply range. All typical values are for T_A = 25°C and V_{CC} = 5.0V.

Note 3: All currents into device pins are shown as positive; all currents out of device pins are shown as negative; all voltages are referenced to ground, unless otherwise specified. All values shown as max. or min. are so classified on absolute value basis.

Note 4: Only one output at a time should be shorted.

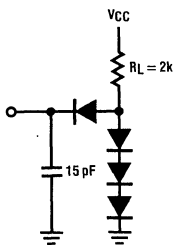
Note 5: Input characteristics do not apply to amplifier inputs (pins 2 & 3).

Note 6: Unless otherwise specified, all AC measurements are referenced to the 1.5V level of the input to the 1.5V level of the output and load circuit 1 is used.

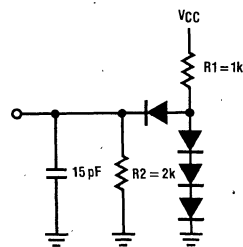
Note 7: AC tests are done with input pulses supplied by generators having the following characteristics: Z_{OUT} = 50Ω, T_r ≤ 5ns, and T_f ≤ 5ns.

Note 8: T = 1/ (clock input frequency), units for "T" should be ns.

Test Load Circuits



Load Circuit 1

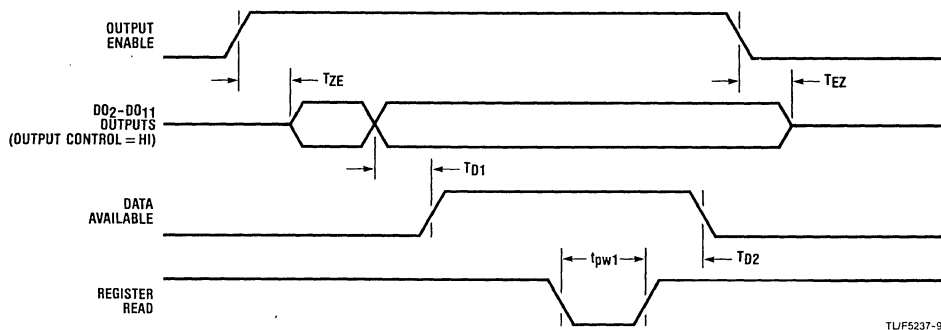


Load Circuit 2

FIGURE 7.

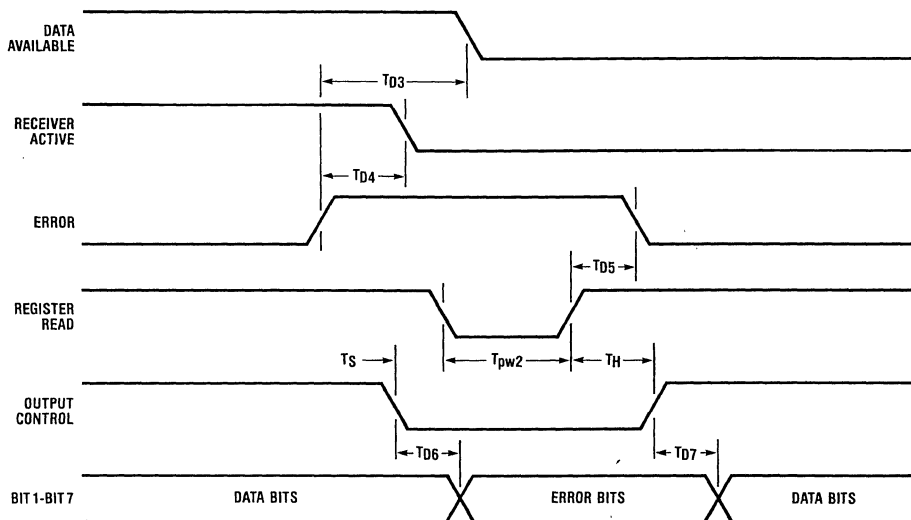
TUF5237-8

Timing Waveforms



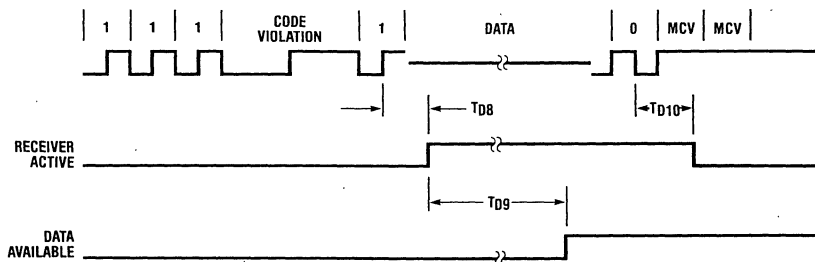
TUF5237-9

FIGURE 8. Data Sequence Timing



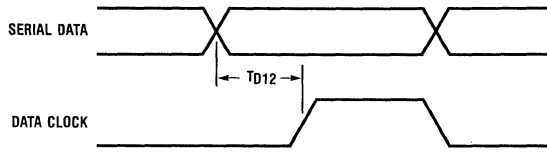
TUF5237-10

FIGURE 9. Error Sequence Timing



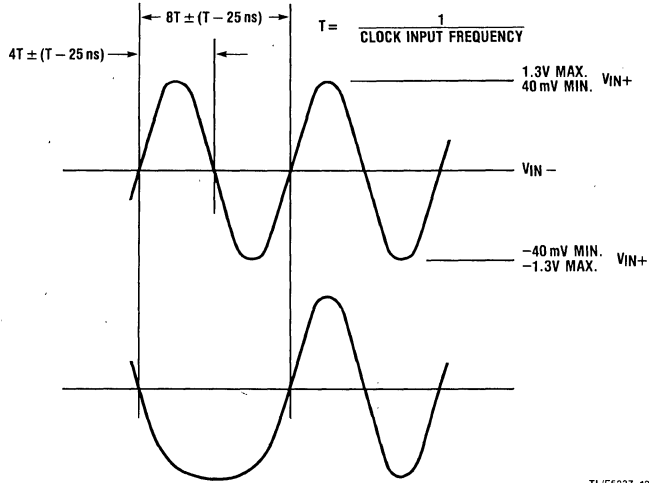
TUF5237-11

FIGURE 10. Message Timing



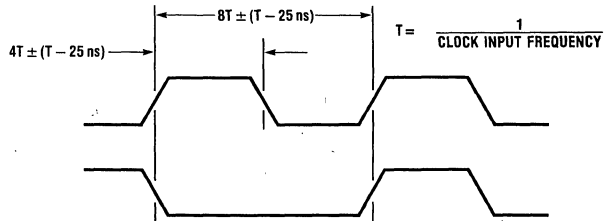
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FIGURE 11. Data Clock and Serial Data Timing



TL/F5237-13

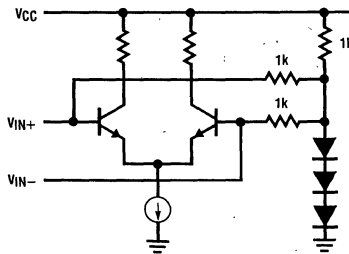
FIGURE 12. Data Waveform Constraints: Amplifier Inputs



Note: $|T_r - T_f| \leq 10 \text{ ns}$

TL/F5237-14

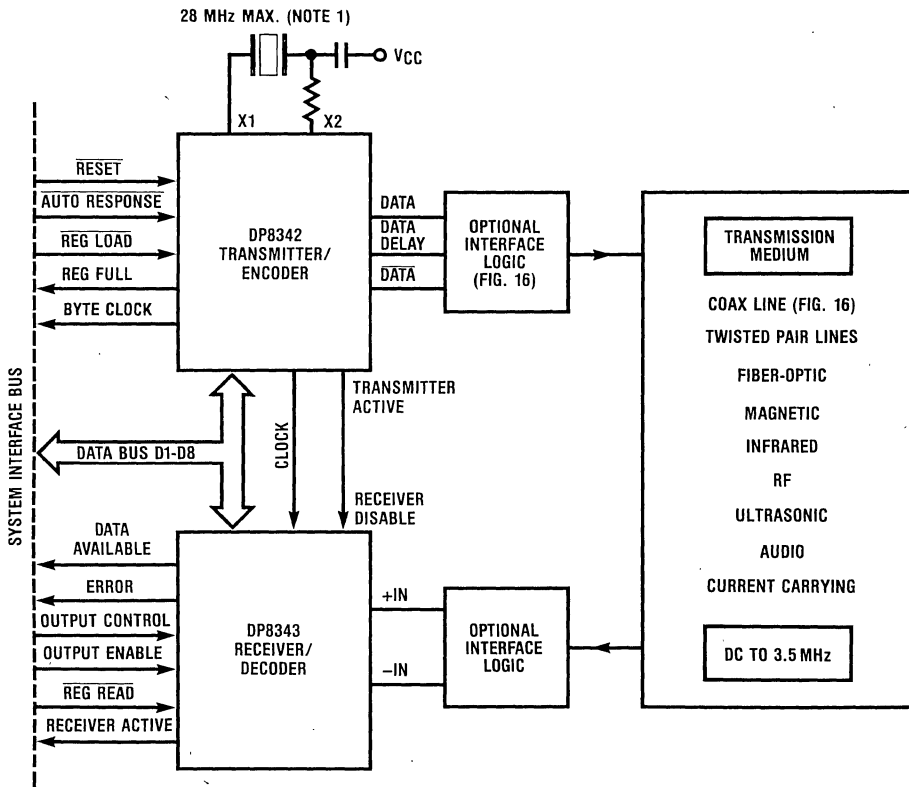
FIGURE 13. Data Waveform Constraints: Data Input (TTL)



TL/F5237-15

FIGURE 14. Equivalent Circuit for DP8343 Input Amplifier

Typical Applications

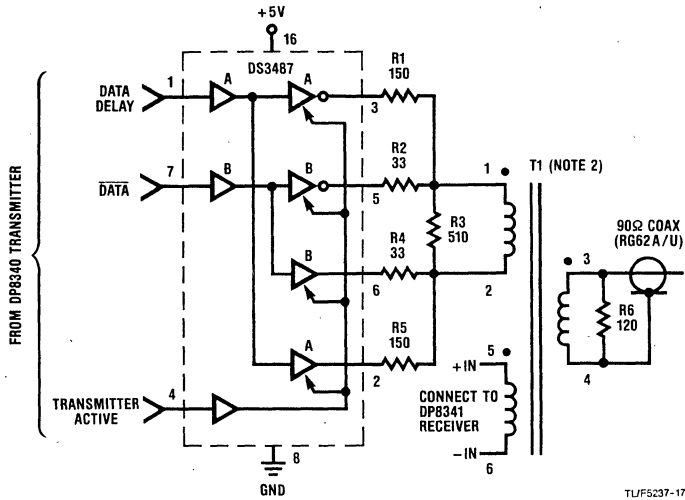


TUF5237-16

Note 1: Crystal manufacturer Midland Ross Corp., NEL Unit Part No. NE-18A @ 28MHz

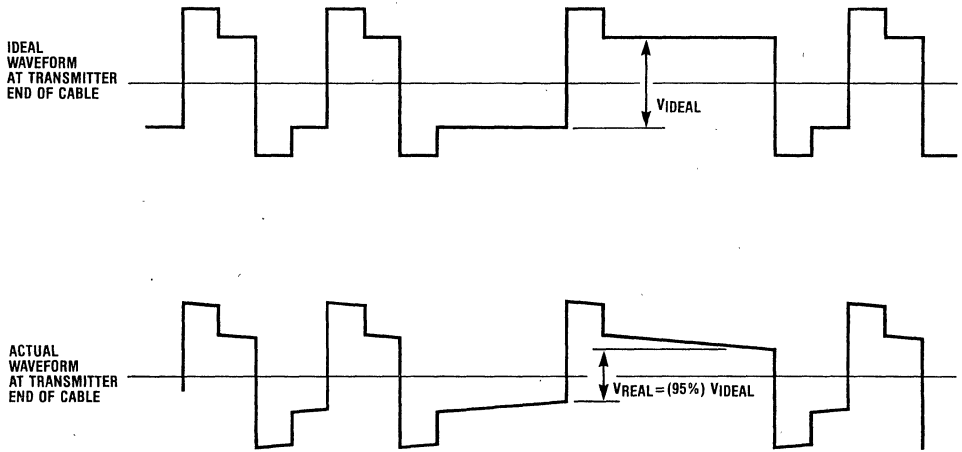
FIGURE 15.

Typical Applications (Continued)



- Notes: 1) Resistance values are in ohms, $\pm 5\%$, $\frac{1}{4}W$.
 2) T1 is a 1:1:1 pulse transformer, $L_{MIN} = 500\mu H$ for 18MHz system clock.
 Pulse Engineering Part No. 5762
 Technitrol Part No. 11LHA or equivalent transformers.

FIGURE 16. Interface Logic for A Coax Transmission Line



* TO MAINTAIN LOSS AT 95% OF IDEAL SIGNAL, SELECT TRANSFORMER INDUCTANCE SUCH THAT:

$$L(MIN) = \frac{10,000}{f_{CLK}} \quad f_{CLK} = \text{SYSTEM CLOCK FREQUENCY (e.g., 18.87 MHz)}$$

EXAMPLE:

$$L = \frac{10,000}{18.87 \times 10^6} \rightarrow L(MIN) = 530\mu H$$

- Notes: 1) Less inductance will cause greater amplitude attenuation.
 2) Greater inductance may decrease signal rise time slightly and increase ringing, but these effects are generally negligible.

FIGURE 17. Transformer Selection



Section 10 Disk Support

10

DEVICE	DESCRIPTION	PAGE NUMBER
AN-334	LSI Components for Winchester Disk Drives and Controllers	10-3
DP8460	Data Separator	10-10
DP8464	Disk Pulse Detector	10-31
DP8466	Disk Data Controller	10-34

LSI Components for Winchester Disk Drives and Controllers

National Semiconductor
Application Note 334
Mike Evans
John Payne
Tim Stout
March 1983



AN-334

INTRODUCTION

Designing an LSI solution for disk system data path electronics requires careful examination of the total disk market place. The objective is to have a high performance solution able to handle state-of-the-art, 14-inch drives while still being reasonably priced for the lower performance, highly cost-sensitive 5 1/4-inch market. The OEM Winchester disk market consists of three main device types: 14-inch, 8-inch and 5 1/4-inch. OEM supplied 14-inch drives range from capacities of 40 megabytes upwards to 1 gigabyte with data rates of 10-24 megabits/second and access times of 25 ms. The 8-inch Winchester drives evolved from scaling of the 14-inch drives and are suitable devices for minicomputer environments. Storage capacities vary from 16 megabytes to 200 megabytes with typical data rates of 7-9 megabits/second and typical access times of 30 ms. The 5 1/4-inch Winchester drive offers a high performance, high capacity version of the established 5 1/4-inch floppy disk. It is thus ideally suited to packaging in microcomputer-based systems. Initially, 5 1/4-inch drives offered 6 megabytes of storage with typical access times of 170 ms. Recently, devices have been announced with storage capacities of over 100 megabytes and access time of 30 ms. Data rates are typically 5 Mbits/second, but will increase.

PERFORMANCE/STANDARDS SET DESIGN AIMS

The rapid evolution of Winchester drives has pushed storage capacities, data rates and access times to the limit. The DP8460 series hard disk chip set has been designed to handle data rates as high as 25 megabits/second to interface with the fastest drives now available. The chip set uses the latest bipolar and CMOS processing techniques as shown in *Figure 1*.

The use of high density run-length-limited codes is well established in the 14-inch market and will migrate to the 8-inch and 5 1/4-inch drives. A further consideration of the design was the ability to work with such codes. Similarly, as storage densities increase, the necessity for ECC (error checking and correcting) electronics becomes apparent. Specific codes have yet to become standard since some in use today are considered inadequate for the future. The hard disk chip set design was required to anticipate such future developments. Furthermore, the design and functional partitioning had to take into account existing standards such as SMD and ANSI X3.101 and yet allow flexibility in areas where standards are still emerging. Finally, the introduction of removable media cartridges places increasing emphasis on programmable format.

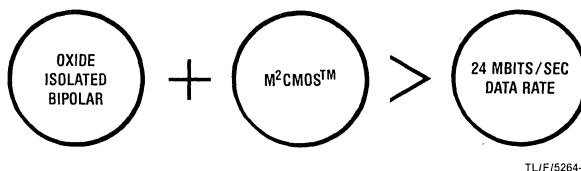


FIGURE 1. Two New Processes Provide Fast Data Rate Capability

FUNCTIONS COMMON TO ALL DISK SYSTEMS

There are certain functions which all disk systems typically perform (Figure 2). As one looks at the data path of a disk system during a read operation, following it from the recording head to the host, there emerge eight well defined functions that are common to all disk drives.

These are:

1. Select the desired head and preamplify the signal from it.
2. Convert the data signal from an analog waveform into a sequence of digital pulses.
3. Generate a clock and synchronized data from the digital pulse train using phase-locked-loop techniques.
4. Decode the synchronized data using the clock.
5. Deserialize the data into byte-wide blocks and byte-align.
6. Identify the desired sector and strip off synchronization information, addressing information, and error check information.
7. Buffer the valid data from the desired sector.
8. Transfer the data into the host's main storage.

Six similar functions are required for writing the data:

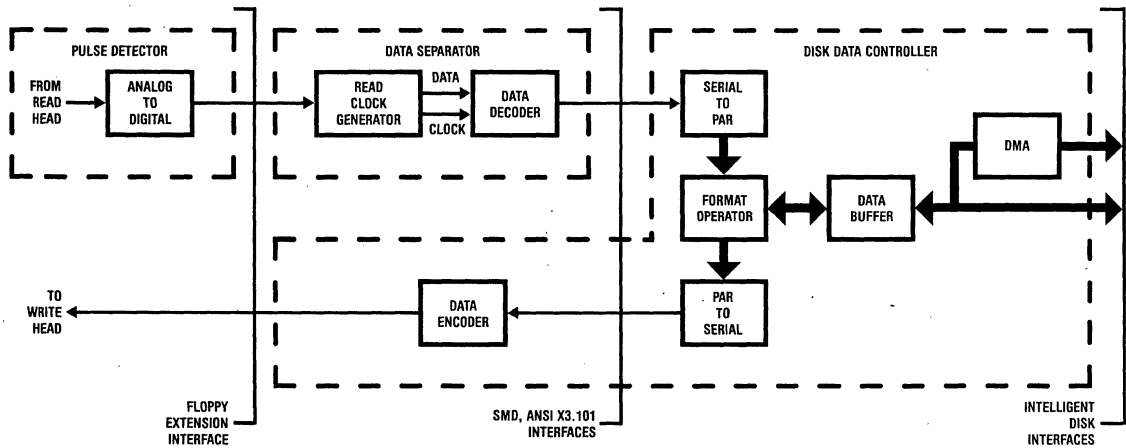
1. Transfer the data out of the host's main storage.
2. Buffer the data.
3. Identify the desired sector, then append synchronization and error checking fields to the data field.
4. Serialize the data.
5. Encode the data.
6. Select the correct recording head and drive it with the encoded data signal.

A disk system is typically separated into two subsystems, the drive and the controller. However, there is no single definition as to which functions are performed in which place, the major disk-to-controller interfaces make the division in different places.

In the floppy extension interface (ST506), the drive performs the functions related to head selection, driving, preamplification, and the analog-to-digital conversion. Everything else is done in the controller. For the SMD and ANSI X3.101 interfaces the drive also performs read clock generation, data decoding, and data encoding. Finally, with the intelligent disk interface, all of the functions are performed by the drive except DMA, which is done by the controller.

The DP8460 series will work with all of the interfaces discussed above. The chips implementing the various functions are placed in the drive or the controller depending upon the particular interface used. The first chips in the set, the pulse detector, data separator, and disk data controller perform all of the functions discussed above with the exception of head operations.

The DP8464 pulse detector converts the analog signal from the head preamplifier into digital pulses. The DP8460 data separator performs read clock generation utilizing an internal phase-locked-loop and data signal decoding. The DP8466 disk data controller performs the remaining functions.



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FIGURE 2. Disk Data Path Functions

DP8464 PULSE DETECTOR

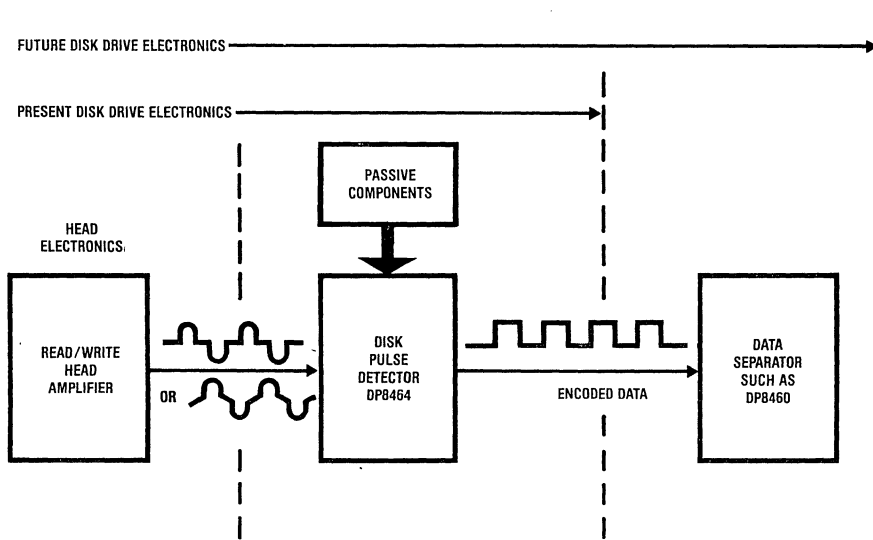
The pulse detector receives the analog signal from the read/write head amplifier and converts the peaks to digital pulses. It is always situated in the disk drive. The primary purpose of the pulse detector is to convert the analog signal received from the recording head into a sequence of digital pulses that can be decoded by the data separator (Figure 3). Each flux reversal of the recording media represents a coded "1"; the absence of a reversal in a given window time represents a coded "0".

The pulse detector sees flux reversals as signal peaks from the recording head, and produces digital output

pulses coinciding with the position of the incoming signal peaks.

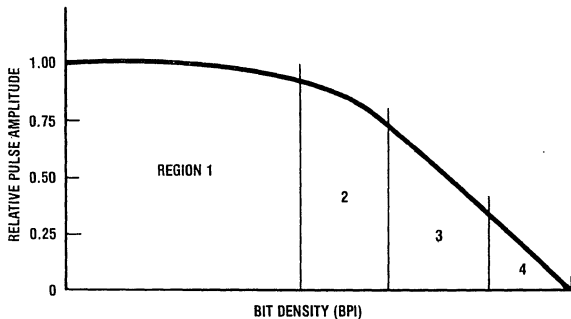
Figure 4a is a plot of relative pulse amplitude versus bits per inch (or recording density). As the recording density increases, bit interaction causes the signal amplitude to decrease.

Pulse shapes as received by the pulse detector are shown in Figure 4b. Regions 1 and 2, the ones predominantly associated with disk drives, are characterized by the analog signal returning to the baseline between pulses.



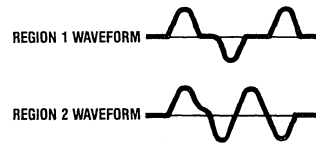
TL/F/5264-3

FIGURE 3. Pulse Detector in a Disk System



TL/F/5264-11

FIGURE 4a. Pulse Amplitude vs Bit Density



TL/F/5264-4

FIGURE 4b. Typical Waveforms

Peak detection is complicated by the susceptibility of the circuitry to noise peaks during this period. The trickiest part of the pulse detector design is to distinguish between signal peaks and noise peaks.

Region 1 is characterized by minimal amplitude distortion with a prolonged return to the baseline. Drives using thin film media or thin film head technology or run-length-limited codes characteristically produce such pulses. The region 1 detector functions by enabling the differentiator from a threshold comparator (Figure 5). Only if the signal is greater than a preset threshold will an output pulse be enabled. Since noise peaks are characteristically of low amplitude, this approach effectively eliminates output pulses due to noise.

Average signal strengths from the recording head will vary from track to track and even along the same track. Hence, use of threshold comparison and signal processing mandates automatic gain control (AGC) circuitry to maintain a constant output from the wideband amplifier.

Region 2 is characterized by some amplitude distortion and a tendency for the signal to return to the baseline. Drives using conventional ferrite heads with MFM typically produce such pulses. The pulse detector will work with most drives operating in regions 1 and 2.

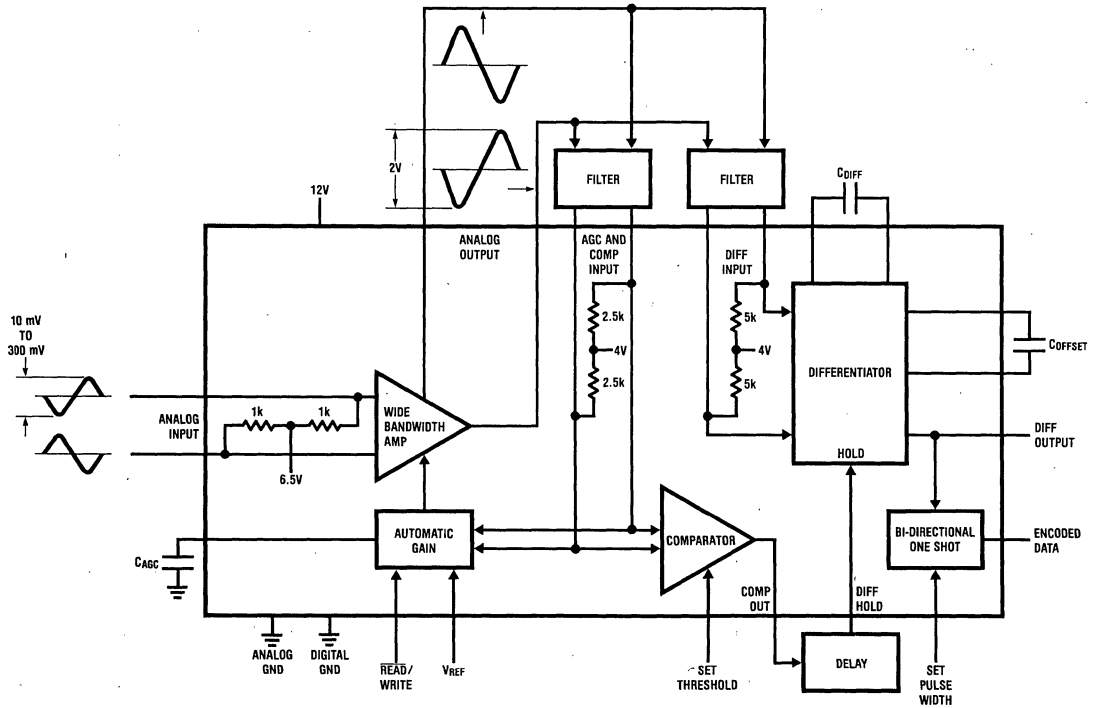
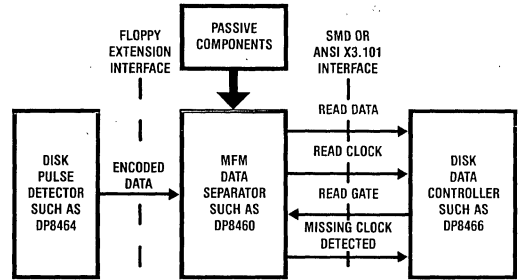


FIGURE 5. Pulse Detector Block Diagram

DATA SEPARATOR

The DP8460 data separator performs the two basic functions of read clock generation (using an internal phase-locked-loop) and MFM decoding (for MFM systems). It is usable with all of the interfaces discussed in this article. It receives encoded data from a pulse detector and outputs data and clock signals to the controller (Figure 6). A block diagram of the chip is shown in Figure 7.



* Soft-sectored disks only

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FIGURE 6. Data Separator in a Hard Disk System

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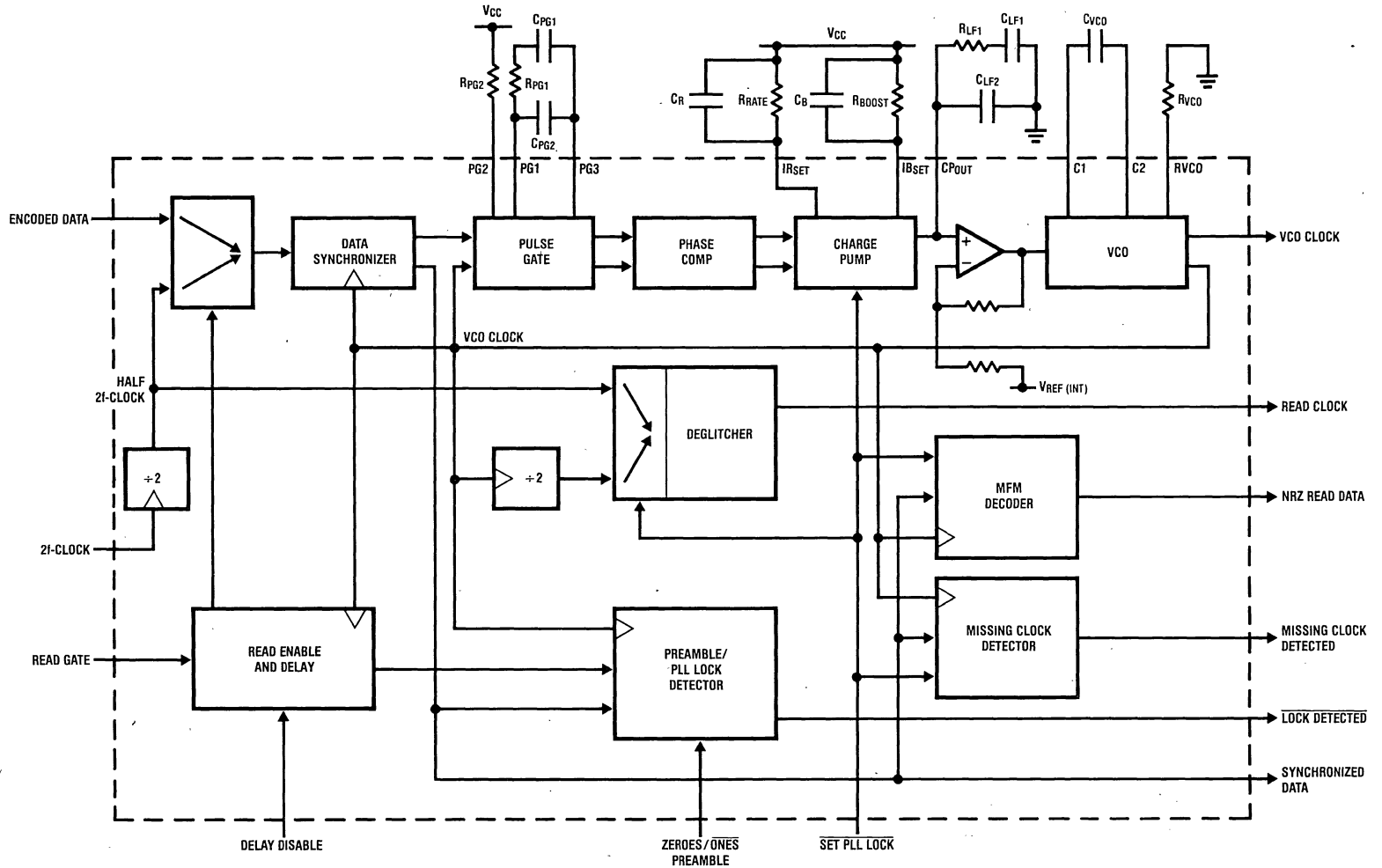


FIGURE 7. Data Separator Detailed Block Diagram

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The upper half of the block diagram is the phase-locked-loop which is the heart of the chip. The PLL may be used with disks employing MFM or run-length-limited codes. A serial data output is derived from the incoming raw data that is synchronized to the clock generated by the PLL. The synchronized data and clock pair then connect to an external data decoder for run-length-limited codes. When MFM encoding is used, the output connects internally to the MFM decoder.

The PLL features two user-selectable tracking rates. A high tracking rate is used while the PLL is locking onto the data stream, but once lock-on is achieved, a more stable and slower tracking rate is used. This offers an extremely quick lock-on time of less than two bytes, while allowing reliable operation by removing bit shift distortions when reading the actual data. The tracking rate switches when the external SET PLL LOCK signal goes active. When the chip is not read-enabled, the PLL tracks an external clock source. In a servo system, this is typically the servo clock, while stepper motor drives use a crystal. This allows the PLL to be at frequency when data decoding begins.

Internal to the phase-locked-loop is a clock gate circuit which delays the data signal by an amount equal to half of the window. No external delay lines are required. The delay is guaranteed to be within a specified narrow time slot for all internal sources of error combined.

To generate the read clock, a clock multiplexer and deglitcher are used. The ANSI X3.101 specification calls for only one clock between the drive and controller, which is a combined read clock/servo clock signal. The SMD specification, on the other hand, specifies both clocks are to be on the interface simultaneously. The chip follows the ANSI specification so that it can work in both systems.

When SET PLL LOCK goes active, the READ CLOCK output switches from external clock to the PLL clock. The switch back takes place when the READ GATE signal goes inactive. The deglitcher ensures that no short clock periods are ever sent to the controller as a result of the switch between the two clocks.

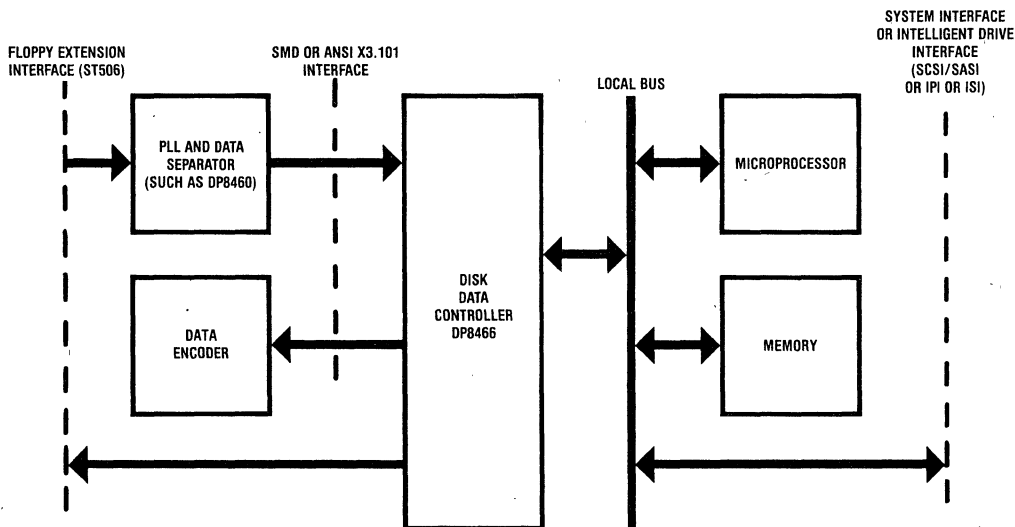
The other portion of the chip is a data decoder that is used with systems using the MFM data code. Before lock-on the MFM decoder assumes that every incoming pulse is a clock pulse and not MFM data. When SET PLL LOCK goes active, the phase pattern between clock pulses and data pulses is frozen to allow decoding of the data. The output of this section is sent to the controller as NRZ READ DATA along with the synchronous READ CLOCK.

The missing clock detector monitors the incoming data pattern for an MFM missing clock violation. If there is an incoming address mark, and a missing clock is detected, the chip activates the signal MISSING CLOCK DETECTED.

DISK DATA CONTROLLER

The DP8466 disk data controller is designed to control the data transfer between the disk drive and the system as shown in *Figure 8*. All other functions are left to a microcontroller or microprocessor. The DDC interfaces to the data separator, on one side, and the system bus or an intelligent disk interface, on the other side. The primary data path functions are to sequence the format field, identify the desired sector, serialize memory data when writing to disk, and to deserialize and byte-align the disk data. Other data path functions performed are data buffering and DMA handling. See *Figure 9* for a block diagram of the chip.

It is inadequate to store data on the disk media directly as received from the host. Various extra fields are needed. The external PLL needs a preamble field in order to achieve lock-on. The deserializer needs a synch field to distinguish the end of the preamble to establish byte boundaries within the serial data stream. Address fields, called headers, are needed to identify and locate specific blocks of data. Error checking and correcting fields are typically appended to the data, as well as various types of postambles and gaps.



TL/F/5264-8

FIGURE 8. Disk Data Controller in a Disk System

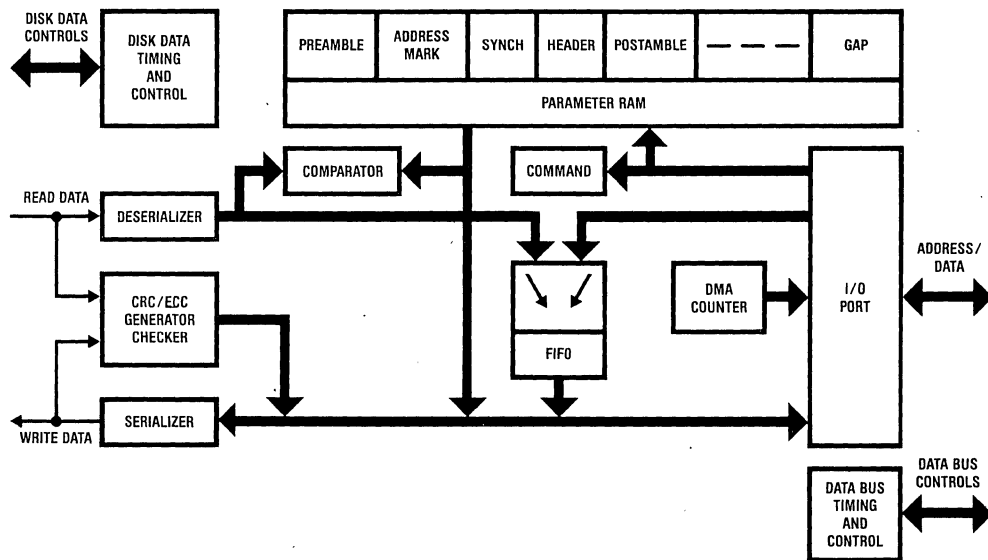


FIGURE 9. Disk Data Controller Block Diagram

TLUF5264-9

FORMAT I



FORMAT II



FORMAT III



FIGURE 10. Typical Disk Formats

TLUF5264-10

The particular sequence and combination of fields used in storing information on the disk is called the format. There is no standard format which is used in all disk drives, but three popular formats are shown in Figure 10. To meet all the different needs of these drives, the chip is externally programmable. The user chooses his own preamble, synch pattern, address mark, postamble and gap, and the order of the format. This is usually performed only once, at initialization. During normal operations such as reading to, or writing from the disk, header information is written to the chip from the microprocessor, along with the mode of operation to be performed such as single or multi-sector, read, or write. Information in the status register or the error register may be accessed.

The serializer converts the parallel data from memory into a serial bitstream and outputs it as NRZ data coincident with the WRITE CLOCK, to interface direct to the SMD or ANSI interfaces. The DDC may also be configured to output MFM encoded data to interface easily to the floppy extension (ST506) interface. The deserializer converts the serial bitstream into byte-wide data for memory. The deserializer features a comparator which is not only used to perform the initial byte-boundary synchronization but is also used in identifying header address.

An internal 32-byte (16-word) FIFO buffers memory data transfers. This FIFO is sufficiently deep to allow extensive microprocessor usage during transfer operations without causing overruns. The chip can be set to transfer data 8 bits or 16 bits at a time. Direct memory access (DMA) capabilities are also included on-chip. A counter provides a 16-bit address field which can be strobed out of the I/O bus prior to valid data. DMA handshake and control signals are provided. This eliminates the need for an external DMA controller chip, and allows faster memory transfers.

Cyclic redundancy check (CRC) or ECC calculations are made on-chip and appended to the data stream when writing, or checked with the CRC/ECC appendage when reading. When the on-chip CRC/ECC codes are undesirable, external circuitry may be used. The disk data controller has two control pins for communication with such circuitry.

Besides the standard features discussed above, the chip has a number of special features. A unique interrupt, called HFASM, notifies the microprocessor that the header failed but the sector numbered matched; this is usually a serious condition requiring immediate attention. If this condition occurs, the last header field read is stored internally and is accessible to the microprocessor. Sector interlocking is available for special microprocessor format sequencing. In multiple sector operations, checkpoint interrupts to the microprocessor are available.

DP8460 Data Separator

General Description

The DP8460 Data Separator is designed for application in disk drive memory systems, and depending on system requirements, may be located either in the drive or in the controller. It receives digital pulses from a pulse detector circuit (such as the DP8464 Disk Pulse Detector), if the DP8460 is situated in the drive, or from the Floppy Extension Interface if it is situated in the controller. After locking on to the frequency of these input pulses, it separates them into synchronized data and clock signals. If the input pulses are MFM encoded data, the data is made available as decoded NRZ data to be deserialized directly by a controller (such as the DP8466 Disk Data Controller). If a run-length-limited code is used, the synchronized data output is available to allow external circuitry to perform the data decoding function. All of the digital input and output signals are TTL compatible and only a single +5V supply is required. The chip is housed in a standard narrow 24-pin dual-in-line package (DIP) and is fabricated using Advanced Schottky bipolar analog and digital circuitry. This high speed I.C. process allows the chip to work with data rates up to 25Mbit/sec. There are three versions of the chip, each having a different decode window error specification. All three versions (-2, -3, -4) will operate from 2 to 25Mbit/sec, with respectively increasing window errors, as specified in the Electrical Characteristics Table.

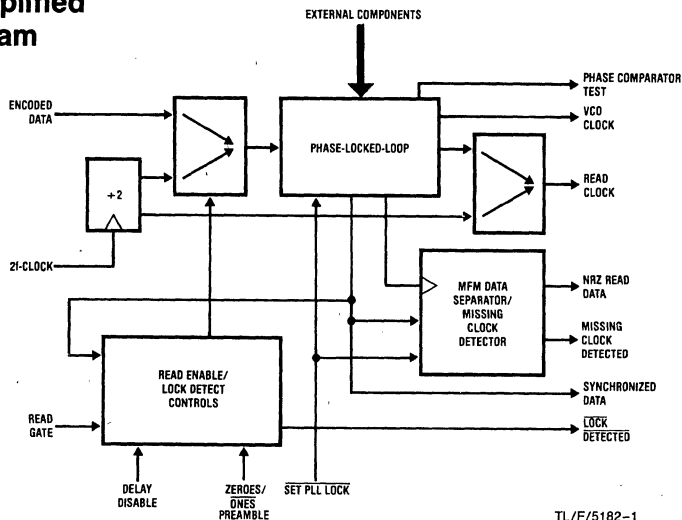
The DP8460 features a phase-lock-loop (PLL) consisting of a pulse gate, phase comparator, charge pump, buffering amplifier, and voltage-controlled-oscillator (VCO). Pins are provided for the user to select the values of the external filtering components required for the pulse gate and amplifier, the frequency setting components required for the VCO, and two current setting resistors for the charge pump. The

DP8460 has been designed to lock on to the incoming preamble data pattern within the first two bytes, using a high rate of charge pump current. Once lock-on has been achieved, the charge pump switches to a lower rate (both rates being determined by the external resistors) to maintain stability for the remainder of the read operation. At this time the READ CLOCK output switches, without glitching, from half the 2f-CLOCK frequency to half the VCO CLOCK frequency. After lock-on, with soft sector disks, the MISSING CLOCK DETECTED output indicates when a missing clock in an address mark field occurs so the controller can align byte boundaries to begin deserialization of the incoming data.

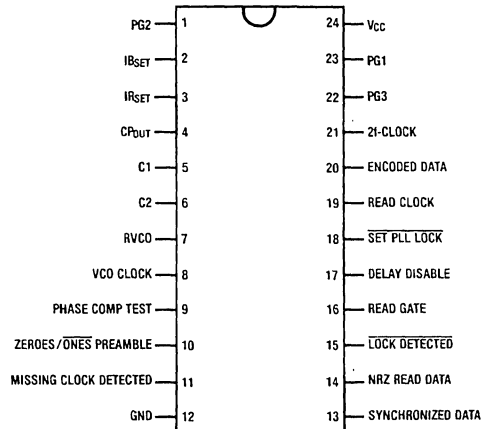
Features

- Operates at data rates up to 25Mbit/sec
- Separates MFM data into read clock and serial NRZ data
- 4 byte preamble-lock indication capability
- Preamble recognition of MFM encoded "0"s or "1"s
- User-determined PLL loop filter network
- PLL charge pump has two user-determined tracking rates
- External control of track rate switchover
- No glitch on READ CLOCK at switchover
- Synchronized data provided as an output (for RLL codes)
- ORed phase comparator outputs for monitoring bit-shift
- Missing clock detected for soft sector disks
- Less than 1/2W power consumption
- Standard narrow 24-pin DIP
- Single +5V supply

DP8460 Simplified Block Diagram



TL/F/5182-1



TOP VIEW

TL/F/5182-2

PIN DEFINITIONS:

Power Supply

24 Vcc +5V ±5%

12 Ground

TTL Level Logic Inputs

16 READ GATE: This is an active high input signal that sets the DP8460 Data Separator into the Read Mode.

17 DELAY DISABLE: This input determines the delay from READ GATE going high to the time the DP8460 enters the Read Mode. If DELAY DISABLE is set high, this delay is within one cycle of the 2f-CLOCK signal. If DELAY DISABLE is set low, the delay is thirty two cycles of the 2f-CLOCK, as shown in Figure 1.

18 SET PLL LOCK: This input allows the user to determine when the on-chip PLL will go into the low track rate. A high level at this input results in the PLL being in the high track rate. If this input is connected to the LOCK DETECTED output, the PLL will go into the low track rate mode immediately after lock is detected.

10 ZEROES/ONES PREAMBLE: A high level on this input enables the circuit to recognize an All Zeros data preamble. A low level results in the recognition of an All Ones data preamble.

20 ENCODED DATA: This input is connected to the output of the head amplifier/pulse-detecting network located in the disk drive. Each positive edge of the ENCODED DATA waveform identifies a change of flux on the disk. In the case of MFM encoded data, the input will be raw MFM.

21 2f-CLOCK: This is a system clock input, which is either a signal generated from the servo track (for systems utilizing servo tracks), or a signal buffered from a crystal.

TTL Level Logic Outputs

8 VCO CLOCK: This is the output of the on-chip VCO, transmitted from an Advanced Schottky-TTL buffer. It is synchronized to the MFM data output and, if needed, it can be used as the 2f-CLOCK for encoding MFM when writing to the disk.

15 LOCK DETECTED: This output goes active low only after both PLL Lock has occurred and the preamble pattern has been recognized. It remains low until READ GATE goes inactive.

14 NRZ READ DATA: This is the NRZ decoded data output, whose leading edges coincide with the trailing edge of READ CLOCK.

13 SYNCHRONIZED DATA: This output is the same encoded data that is input to the chip, but is synchronous with the negative edge of the VCO CLOCK.

11 MISSING CLOCK DETECTED: When a missing clock is detected, this output will be a single pulse (of width equal to one cycle of READ CLOCK) occurring as shown in Figure 2.

19 READ CLOCK: This is half VCO CLOCK frequency during read mode after PLL Lock; it is half 2f-CLOCK frequency at all other times. A deglitcher is utilized to ensure that no short clock periods occur during either switchover.

9 PHASE COMP TEST: This output is the logical "OR" of the Phase Comparator outputs, and may be used for the testing of the disk media.

Analog Signals

23, 22, PG1, PG3: The external capacitors and resistor of the Pulse Gate filter are connected to these pins.

1 PG2: This is the Pulse Gate current supply.

3 IRSET: The current into the rate set pin (V_{BE}/R_{Rate}) is half the charge pump output current for the slow tracking rate.

2 IBSET: The current into the boost set pin (V_{BE}/R_{Boost}) is half the amount by which the charge pump current is increased for the high tracking rate. ($I_{HIRATE} = I_{RATE Set} + I_{BOOST Set}$).

4 CPOUT: CHARGE PUMP OUT/BUFFER AMP IN is available for connection of external filter components, for the phase-lock-loop. In addition to being the charge pump output node, this pin is also the noninverting input to the op-amp of the Buffer Amplifier.

7 RVCO: The current into this pin determines the operating currents within the VCO.

5, 6 VCO C1, C2: An external capacitor connected across these pins sets the nominal VCO frequency.

Absolute Maximum Ratings

Supply Voltage	7V
TTL Inputs	7V
Output Voltages	7V
Input Current (CPOUT, IRSET, IBSET, RVCO)	2mA
Storage Temperature	-65°C to 150°C

Operating Conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V _{CC}	Supply Voltage		4.75	5.00	5.25	V
T _A	Ambient Temperature		0	25	70	°C
I _{OH}	High Logic Level Output Current	V _{CC} Clock Others			-2000 -400	μA
I _{OL}	Low Logic Level Output Current	V _{CC} Clock Others			20 8	mA
f _{DATA}	Input Data Rate		2.0		25	Mbit/sec
t _{WCK}	Width of 2f-CLOCK, High or Low		10			ns
t _{WPD}	Width of ENCODED DATA Pulse, High or Low (Note 2)		0.25t			ns
V _{IH}	High Logic Level Input Voltage		2			V
V _{IL}	Low Logic Level Input Voltage				0.8	V

DC Electrical Characteristics Over Recommended Operating Temperature Range

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V _{IC}	Input Clamp Voltage	V _{CC} = Min., I _I = -18mA			-1.5	V
V _{OH}	High Level Output Voltage	V _{CC} = Min., I _{OH} = Max.	V _{CC} -2V	V _{CC} -1.6V		V
V _{OL}	Low Level Output Voltage	V _{CC} = Min., I _{OL} = Max.			0.5	V
I _{IH}	High Level Input Current	V _{CC} = Max., V _I = 2.7V			20	μA
I _{IL}	Low Level Input Current	V _{CC} = Max., V _I = 0.4V			-200	μA
I _O	Output Drive Current	V _{CC} = Max., V _O = 2.125V ¹	-30		-110	mA
I _{CC}	Supply Current	V _{CC} = Max.			100	mA
I _{OUT}	Charge Pump Output Current	I _{RSET} = V _{BE} /R _{RATE} I _{BSET} = V _{BE} /R _{BOOST}	-10% -10%	2×I _{RSET} 2×(I _{RSET} +I _{BSET})	+10% +10%	mA

1. This value has been chosen to produce a current that closely approximates one-half of the true short-circuit output current, I_{OS}.

2. t is defined as the period of the encoded data

AC Electrical Characteristics Over Recommended V_{CC} and Operating Temperature Range.

(All Parts unless stated otherwise) (t_R = t_F = 2.0ns, V_{IH} = 3.0V, V_{IL} = 0V)

Symbol	Parameter	Min	Typ	Max	Units
t _{READ}	Positive READ CLOCK transitions from READ GATE set active until PLL Lock sequence begins (DELAY DISABLE low)		16	17	—
t _{READ}	Positive READ CLOCK transitions from READ GATE set active until PLL Lock sequence begins (DELAY DISABLE high)		1	1	—
t _{DECODE NRZ}	Number of READ CLOCK cycles required to output each decoded MFM data bit ⁴	—	2	3	T-clock
t _{TRANSMIT MFM}	Positive READ CLOCK transitions required to transmit input MFM to output	1	2	3	—
t _{READ ABORT}	Number of READ CLOCK cycles after READ GATE set low to read operation abort			2	T-clock
t _{WINDOW}	Variance of center of decode window from nominal ⁷	DP8460-2 DP8460-3 DP8460-4		2+0.6%τ 3+0.8%τ 4+1.0%τ	ns
φ _{LINEARITY}	Phase range for charge pump output linearity ²	-π		+π	Radians
K ₁	Phase Comparator — Charge Pump gain constant ⁵		$\frac{V_{BE}}{\pi R}$		Amps/rad
V _{CONTROL}	Charge pump output voltage swing from nominal		±100		mV
K _{VCO} (=A×K ₂)	VCO gain constant (ω _{VCO} = VCO center frequency in rad/s) ⁶	$\frac{1.4\omega_C}{V_{BE}}$	$\frac{1.6\omega_C}{V_{BE}}$	$\frac{1.8\omega_C}{V_{BE}}$	rad/sec. V
f _{VCO}	VCO center frequency variation over temperature and V _{CC}	-5		+5	%
f _{MAX VCO}	VCO maximum frequency	70			MHz
t _{HOLD}	Time READ CLOCK is held low during changeover after lock detection has occurred ³			1½	T-clock
t _{MFSKEW}	Output skew between VCO clock and Synchronized Data				ns
t _{NRZSKEW}	Output skew between READ CLOCK, NRZ READ DATA and MISSING CLOCK DETECTED				ns

1. A sample calculation of frequency variation vs. control voltage: V_{IN} = ±0.2V; $K_{VCO} = \frac{\omega_{OUT}}{V_{IN}} = \frac{0.4 \omega_C}{0.2V} = \frac{2.0 \omega_C}{V}$ (rad/sec) (volt)

2. -π to +π with respect to 2f VCO CLOCK

3. T-clock is defined as the time required for one period of the READ CLOCK to occur.

4. This number remains fixed after PLL Lock occurs.

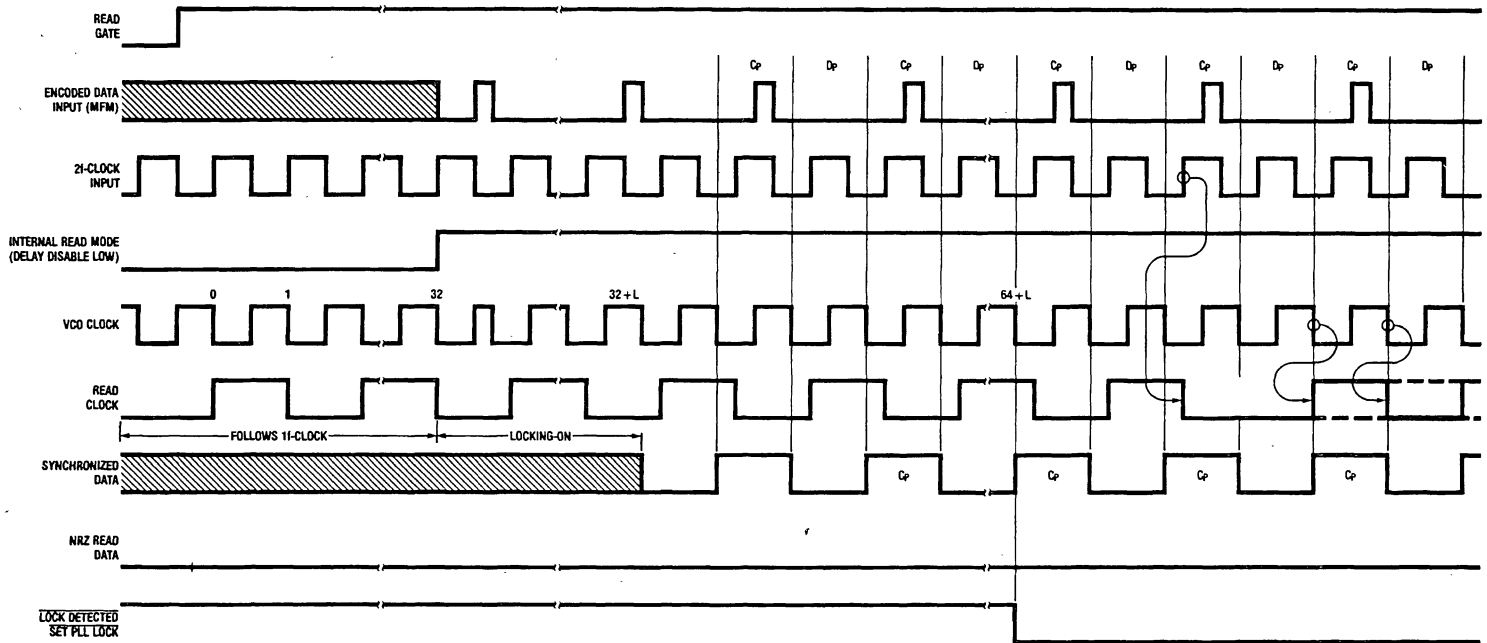
5. With respect to VCO CLOCK; I_{PUMP OUT} = 2 I_{SET}
 $I_{SET} = \frac{V_{BE}}{R_{SET}}$

6. Although specified as the VCO gain constant, this is the gain from the Buffer Amplifier input to the VCO output.

7. τ is defined as the period of the incoming data stream

External Component Selection (All Parts)

Symbol	Component	Min	Typ	Max	Unit
R _{VCO}	VCO Frequency Setting Resistor	990		1010	Ω
C _{VCO}	VCO Frequency Setting Capacitor	15			pF
R _{LF}	Loop Filter Resistor	TBD		TBD	Ω
C _{LF1}	Loop Filter Capacitor 1	20		TBD	pF
C _{LF2}	Loop Filter Capacitor 2	20		TBD	pF
R _{RATE}	Charge Pump I _{RATE} Set Resistor	1.2		6.5	kΩ
R _{BOOST}	Charge Pump (High Rate) I _{BOOST} Resistor	0.4		∞	kΩ
R _{PG2}	Delay Time Setting Resistor	0		150	kΩ
R _{PG1}	Pulse Gate Resistor	TBD		TBD	kΩ
C _{PG1}	Pulse Gate Capacitor C1	20		TBD	pF
C _{PG2}	Pulse Gate Capacitor C2	20		TBD	pF
C _R	I _{RATE} Bypass Capacitor	1000			pF
C _B	I _{BOOST} Bypass Capacitor	1000			pF



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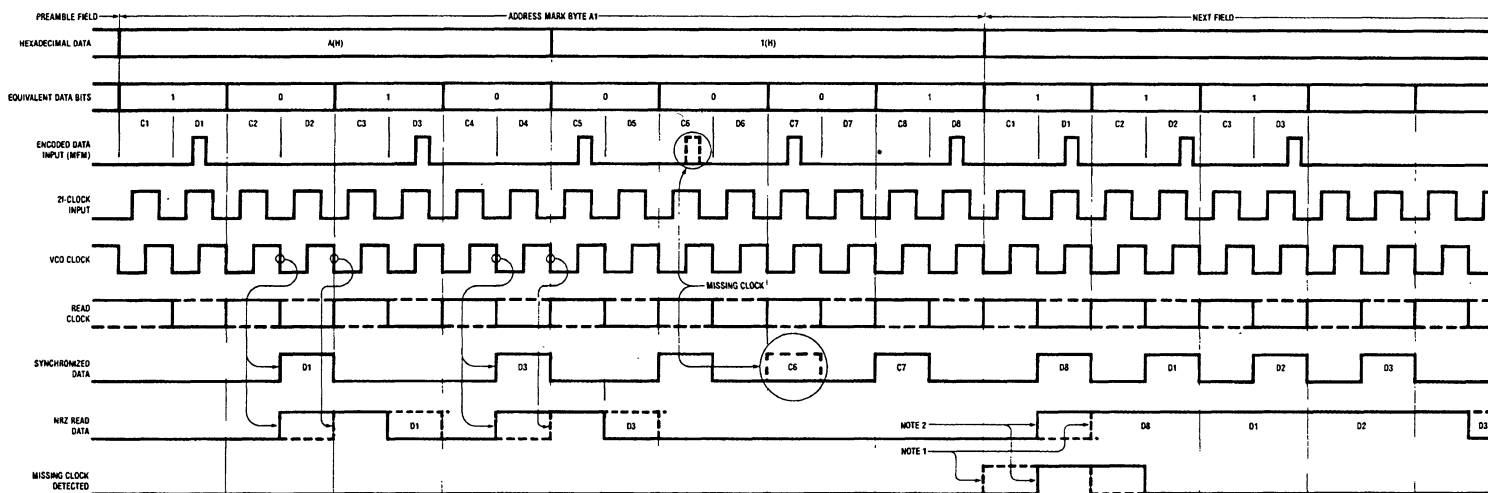
C_P , D_P = preamble clock and preamble data bits respectively.

L = Number of 2f-clock cycles required for VCO to lock (typically ≈ 20 2f-clock cycles), but determined by external component values

At $32 + L$, VCO has just locked.

At $64 + L$, circuit has confirmed lock (has been in lock for 16 MFM clock bits). This sequence shows the MFM preamble pattern.

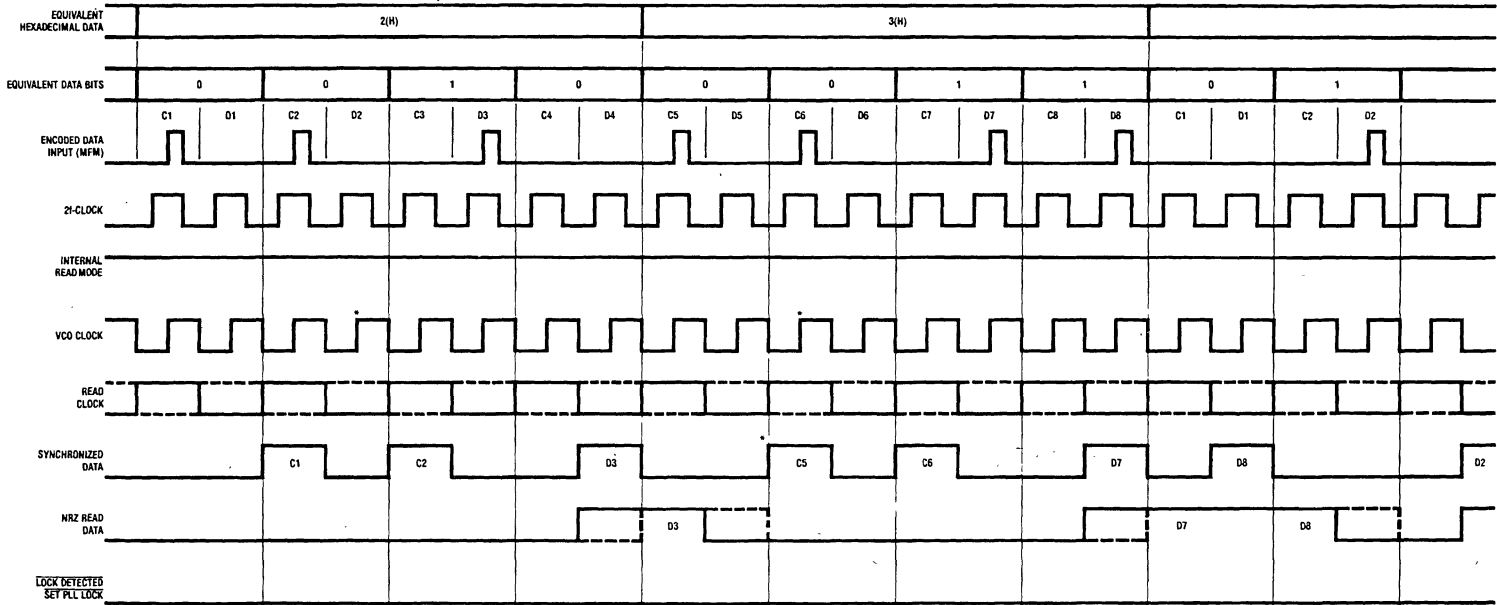
FIGURE 1. Lock-on Sequence Waveform Diagram



- * READ CLOCK and NRZ READ DATA may be delayed by one VCO clock period depending on the phase of the internal clock at activation of READ GATE input.
- ① MISSING CLOCK DETECTED is one READ CLOCK period ahead of the chip issuing D8 on the NRZ READ DATA output when READ CLOCK is delayed by one VCO clock period
- ② MISSING CLOCK DETECTED is synchronous with the chip issuing D8 on the NRZ READ DATA Output when READ CLOCK is not delayed

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FIGURE 2. Missing Clock Detection Waveform Diagram

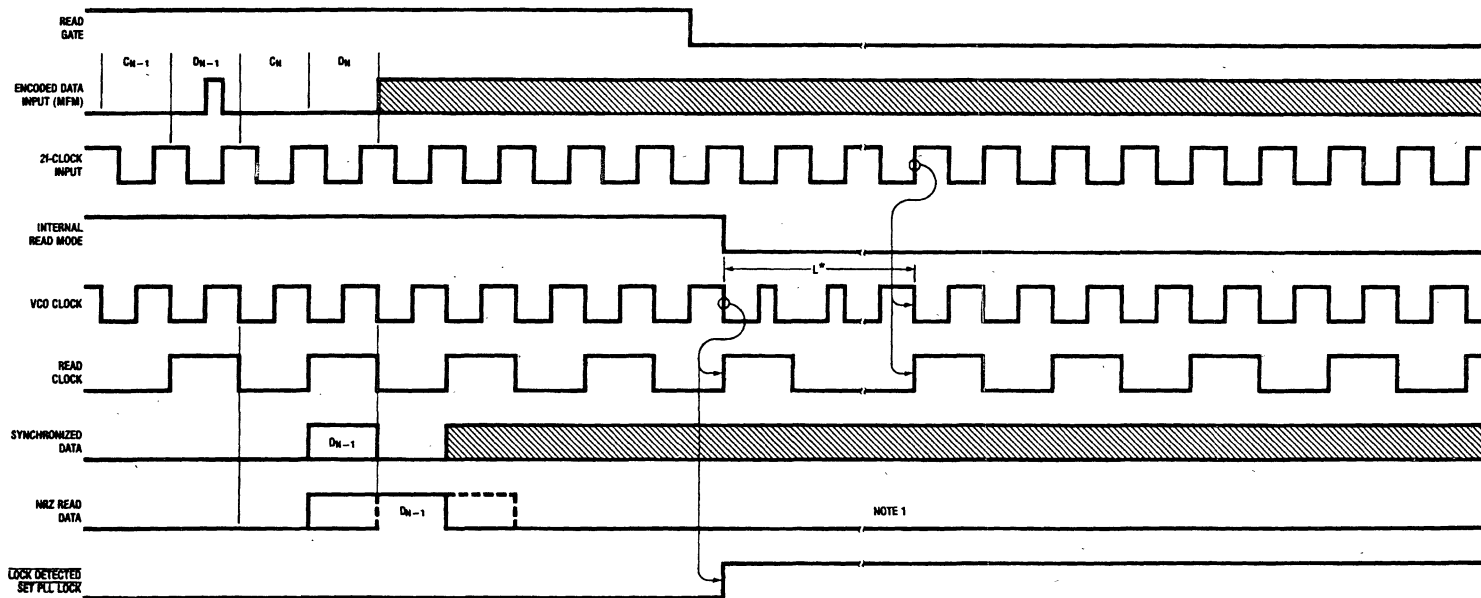


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* READ CLOCK and NRZ READ DATA may be delayed by one VCO clock period with respect to Synchronized Data depending on the phase of the internal clock at activation of READ GATE input.

FIGURE 3. Locked-on Waveform Diagram

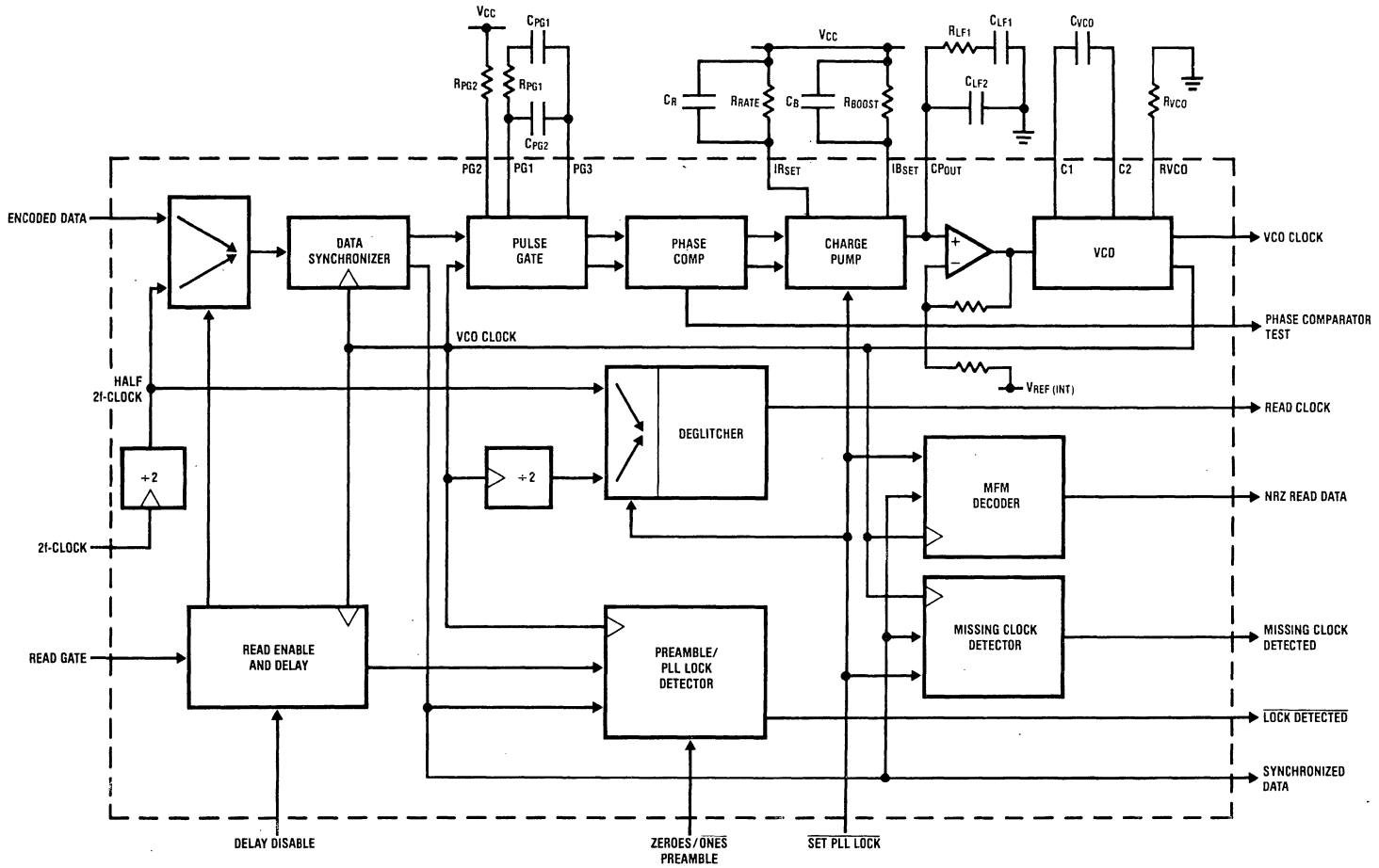
10-18



* L indicates the number of cycles required for the VCO to lock to the 2f-CLOCK
 NOTE 1: READ GATE going low will always result in NRZ READ DATA going low regardless of the state of the last bit

FIGURE 4. Lock-Ending Sequence Waveform Diagram

DP8460 Detailed Block Diagram



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10-19

CIRCUIT OPERATION

When the READ GATE input goes high, the DP8460 Data Separator enters the read mode after a period determined by the state of the DELAY DISABLE pin. This may be either one or thirty two 2f-CLOCK cycles. Referring to *Figure 1*, once in the read mode, the phase-locked-loop reference signal is switched from 2f-CLOCK input to the ENCODED DATA input. The PLL, initially in the high-tracking rate mode, then attempts to lock onto the incoming encoded data stream. By careful selection of the loop filter components, this can be within 2 bytes. Preamble pattern recognition then can begin. As soon as two bytes of the selected preamble are detected, (the selection is determined by the ZEROES/ONES PREAMBLE pin) the LOCK DETECTED output goes low. In a typical MFM disk drive application, the LOCK DETECTED output is directly connected to the SET PLL LOCK input. With this connection, track rate selection, clock output switchover, and data output enabling will occur after four consecutive preamble bytes have been fed into the chip, from the time the read mode began.

A low level on the SET PLL LOCK causes the PLL Charge Pump to switch from the high to low tracking rate. At the same time the source of the READ CLOCK signal is switched from half the frequency of the 2f-CLOCK to half the VCO clock. The MFM decoder also becomes enabled and begins to output decoded NRZ data. If the preamble is being decoded, and it is a zeroes data preamble, the NRZ READ DATA output will remain low until the end of the preamble. It will then output NRZ data some 2f-CLOCK periods after the preamble field has ended, as shown in *Figures 2* and *3*.

Figure 4 shows the sequence when READ GATE goes low, signifying the end of a read operation. The PLL reference signal is switched back to half the 2f-CLOCK and the LOCK DETECTED output (and therefore the SET PLL LOCK input) goes high. The PLL then returns to the high tracking rate, and the output signals return to their initial conditions.

CIRCUIT DESCRIPTION

1. Read Enable and Delay: If the DELAY DISABLE input is connected low, then thirty two 2f-CLOCK cycles after READ GATE goes active, the DP8460 will go into the read mode. If the DELAY DISABLE input is connected high, the chip will go into the read mode one 2f-CLOCK cycle after READ GATE goes active. This feature allows the user to choose the time at which the PLL Lock Sequence begins and thus accommodates systems with short preambles.

2. Pulse Gate, including Input Multiplexer and Data Synchronizer: The Input Multiplexer selects the input to the phase-lock-loop. While the chip is in the bypassed mode, the PLL is locked on half the 2f-CLOCK frequency, but in the read mode, the Input Multiplexer switches to the ENCODED DATA signal. The VCO CLOCK then begins to synchronize with the ENCODED DATA signal. The Pulse Gate allows a reference signal from the VCO into the Phase Comparator only when an ENCODED DATA bit is valid. The Pulse Gate utilizes a scheme which delays the incoming data by one-half the period of the 2f-CLOCK. This optimizes the position of the decode window and allows input jitter up to \pm half the 2f-CLOCK period, assuming no error in the decode window position. The decode window error can be determined from the specification in the Electrical Characteristics Table.

3. Phase Comparator: The Phase Comparator receives its inputs from the Pulse Gate, and is edge-triggered from these inputs to provide charge-up and charge-down outputs.

4. Charge Pump: The high speed charge pump consists of a switchable constant current source and sink. The charge pump constant current is set by connecting external resistors to Vcc from the charge current rate set (IRSET) and current boost set (IBSET) pins. Before lock is indicated, the PLL is in the fast tracking rate and both resistors determine the current. In the slow tracking rate after lock-on, only the IRSET resistor determines the charge pump current. The output of the charge pump feeds into external filter components and the Buffer Amplifier.

5. Buffer Amplifier: The input of the Buffer Amplifier is internally connected to the charge pump's constant current source/sink output as well as the external Loop Filter components. The Buffer Amplifier is configured as a high input impedance amplifier which allows for the connection of external PLL filter components to the Charge Pump output pin CPOUT. The output of the Buffer Amplifier is internally connected to the VCO control input.

6. VCO: The Voltage-Controlled-Oscillator requires a resistor from the RVCO pin to ground and a capacitor between pins C1 and C2, to set the center frequency. The VCO frequency can be varied from nominal by approximately $\pm 20\%$, as determined by its control input voltage.

7. PLL Lock-on/Preamble Pattern Detector: To recognize preamble, the preamble pattern from the disk must consist exclusively of either data bit zeroes (encoded into ..10.. MFM clock pulses) when the ZEROES/ONES PREAMBLE pin is set high, or data bit ones (encoded into ..01.. MFM clock pulses) when set low. The preamble pattern must be long enough to allow the PLL to lock, and subsequently for the Preamble Pattern Detector circuit to detect two complete bytes.

Once the chip is in the read mode, the VCO proceeds to lock on to the incoming data stream. The Preamble Pattern Detector then searches for a continuous pattern of 10101010101010101010101010101010 (16 consecutive pulses at the data rate) to indicate lock has been achieved. The LOCK DETECTED output then goes low.

Any deviation from the above-mentioned one-zero pattern at any time before PLL Lock is detected will reset the PLL Lock Detector. The lock detection procedure will then start again.

8. MFM Decoder: The MFM Decoder receives synchronized MFM data from the Pulse Gate and converts it to NRZ READ DATA. For run-length-limited codes the MFM Decoder and Missing Clock Detector will not be used.

9. Missing Clock Detector: This block is only required for soft-sectored drives, and is used to detect a missing clock violation of the MFM pattern. The missing clock is inserted when writing to soft-sectored disks to indicate the location of the Address Mark in both the ID and the Data fields of each sector. Once PLL Lock has been indicated, the Missing Clock Detector circuit is enabled. MISSING CLOCK DETECTED will go active only if the incoming data pattern contains one suppressed clock bit framed by two adjacent clock bits. The output signal goes high for one cycle of READ CLOCK.

10. Clock Multiplexer and Deglitcher: When the SET PLL LOCK input changes state this circuit switches the source of the READ CLOCK signal between the half 2f-CLOCK frequency and the half VCO CLOCK frequency. A deglitcher circuit is utilized to ensure that no short clock periods occur during either switchover.

BIT-JITTER TOLERANCE

The three options of the DP8460, the -4, -3 and -2 offer decreasing window errors (respectively) so that the parts may be selected for different data rates (up to 25Mbit/sec). The -4 part will be used in most low data rate applications. As an example, at the 5Mbit/sec data rate of most 5¼ inch drives, $T = 200\text{ns}$ so that from the Electrical Characteristics Table, $t_{\text{WINDOW}} = (4 + (1\% \text{ of } 200\text{ns}))$ or 6ns. The chip therefore contributes up to 6ns of window error, out of the total allowable error of 50ns (half the 2f-clock period of 100ns). This allows the disk drive to have a margin of 44ns of jitter on the transition position before an error will occur.

ANALOG CONNECTIONS TO THE DP8460

External passive components are required for the Pulse Gate, Charge Pump, Loop Filter and VCO as shown in Figure 5. The information provided here is for guidelines only. The user should select values according to his own system requirements. Phase-Locked Loops are complex circuits that require detailed knowledge of the specific system. Factors such as loop gain, stability, response to change of signal, lock-on time, etc are all determined by the external components. In many disk systems these factors are critical, and National Semiconductor recommends the designer be knowledgeable of phase-locked-loops, or seek the advice of an expert. Inaccurate design will probably result in excessive disk error rates. The phase-locked-loop in the DP8460 has many advantages over all but the most sophisticated discrete designs, and if the component values are selected correctly, it will offer significant performance advantages. This should result in a reduction of disk error rates over equivalent discrete designs.

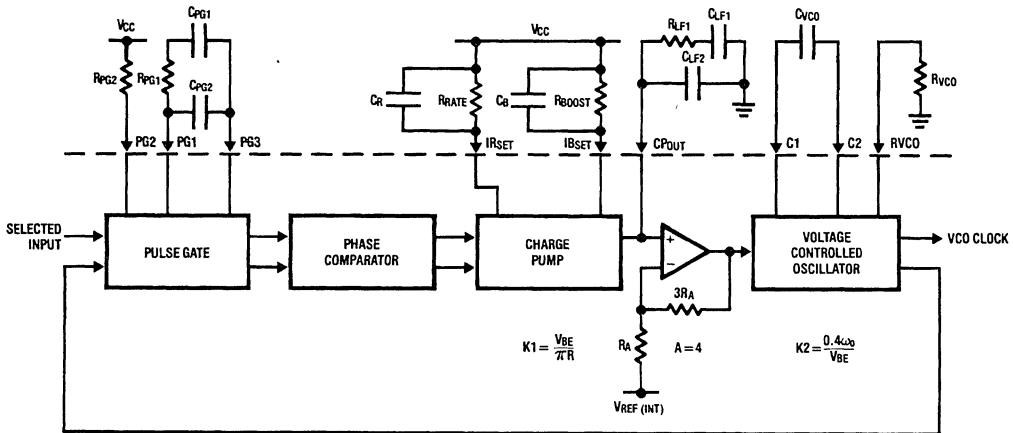


FIGURE 5. Phase-Locked-Loop Section

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Pulse Gate

There are four external components connected to the Pulse Gate as shown in *Figure 6* with the associated internal components. The values of R_{PG1} , R_{PG2} , C_{PG1} , and C_{PG2} are dependent on the data rate. R_{PG1} is proportional to the data rate, while R_{PG2} , C_{PG1} and C_{PG2} are inversely proportional. Table 1 shows component values for the data rates given. For other data rates, use the equations $R_{PG1} = (TBD \times f_{VCO})$ k Ω , $R_{PG2} = ((TBD / f_{VCO}) - 0.89)$ k Ω , $C_{PG1} = (TBD / f_{VCO})$ pF and $C_{PG2} = (TBD / f_{VCO})$ pF, where f_{VCO} is the VCO frequency in MHz. As an example, at 5Mbits/sec data rate, $f_{VCO} = 10$ MHz. This produces $R_{PG1} = \dots$ k Ω , $R_{PG2} = \dots$ k Ω , $C_{PG1} = \dots$ pF and $C_{PG2} = \dots$ pF. Components with 5% tolerance will suffice.

Data Rate	R_{PG2}	R_{PG1}	C_{PG1}	C_{PG2}
2Mbit/sec	16k Ω			
5Mbit/sec	4.7k Ω			
10Mbit/sec	1.9k Ω			
15Mbit/sec	750 Ω			
20Mbit/sec	300 Ω			
25Mbit/sec	0			

TABLE 1. Pulse Gate Component Selection Chart

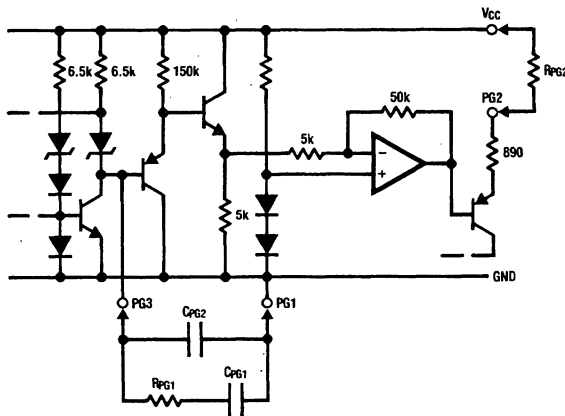


FIGURE 6. Pulse Gate Controls

Charge Pump

Resistors R_{RATE} and R_{BOOST} determine the charge pump current. The Charge Pump bidirectional output current is approximately (within $\pm 10\%$) twice the input current. In the high tracking rate with SET PLL LOCK high, the input current is $I_{BSET} + I_{RSET}$, ie, the sum of the currents through R_{BOOST} and R_{RATE} from Vcc. In the low tracking rate, with SET PLL LOCK low, this input current is I_{RSET} only.

A recommended approach would be to select R_{RATE} first. The External Component Limits table allows R_{RATE} to be 1.2k Ω to 6.5k Ω , so for simplicity select $R_{RATE} = 3.3k\Omega$. A typical loop gain change of 4:1 for high to low tracking rate would require $R_{BOOST} = R_{RATE} / 3$ or 1.1k Ω . Referring to *Figure 7* the input current is effectively V_{BE} / R_{RATE} in the low tracking rate, where V_{BE} is an internal voltage. This means that the current into or out of the loop filter is approximately $2 V_{BE} / R_{RATE}$, or in this example approximately 0.4mA. Note that although it would seem the overall gain is dependent on V_{BE} , this is not the case. The loop gain is altered internally by an amount inversely proportional to V_{BE} , as detailed in the section on the Loop Filter. This means that as V_{BE} varies with temperature or device spread, the gain will remain constant for a particular fixed values of R_{RATE} and R_{BOOST} . This alleviates the need for potentiometers to select values for each device. The tolerance required for these two resistors will depend on the total loop gain tolerance allowed, but 5% would be typical. Also Vcc by-pass capacitors are required for these two resistors. A value of 1000pF is suitable for each.

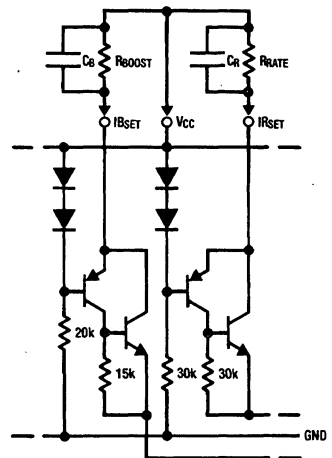


FIGURE 7. I_{RATE} Set and I_{BOOST} Set

TL/F/5182-9

TL/F/5182-10

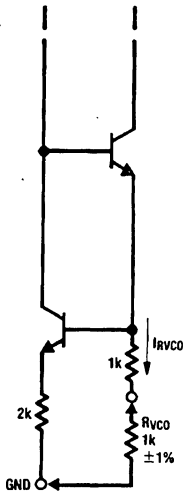
VCO

The value of R_{VCO} is fixed at $1\text{ k}\Omega \pm 1\%$ in the External Component Limits table. This requires a resistor more accurate than 1% to allow for temperature variations. *Figure 8* shows how R_{VCO} is connected to the internal components of the chip. This value was fixed at $1\text{ k}\Omega$ to set the VCO operating current such that optimum performance of the VCO is obtained for production device spreads. This means fixed value components will be adequate to set the VCO center frequency for production runs. The value of C_{VCO} can therefore be determined from the VCO frequency f_{VCO} , using the equation: $C_{VCO} = 1 / (R_{VCO}) (f_{VCO})$ where f_{VCO} is twice the input data rate. As an example, for a 5Mbit/sec data rate, $f_{VCO} = 10\text{MHz}$, requiring that $C_{VCO} = 100\text{pF}$. The

capacitor tolerance also should be better than 1%. The capacitor is connected to internal circuitry of the chip as shown in *Figure 9*.

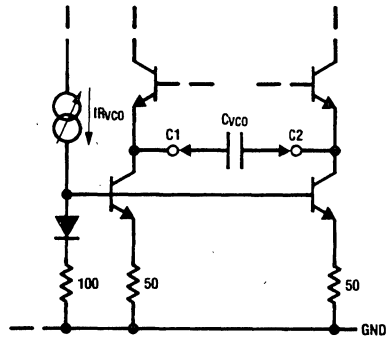
This equation does not cover the whole range of data rates. As the data rate increases and C_{VCO} gets smaller, the effects of unwanted parasitic capacitances influence the frequency. As a guide the graph of *Figure 10* shows approximately the value of C_{VCO} for a given data rate.

The center frequency may be checked by applying pulses at the ENCODED DATA input with READ GATE set high. The input frequency should be varied above and below the chosen center frequency until the VCO stops tracking. Typically this will be 20% either side of the center frequency.



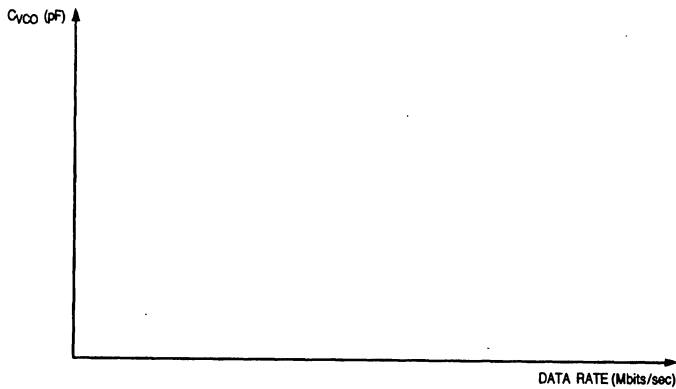
TL/F/5182-11

FIGURE 8. VCO Current Setting Resistor



TL/F/5182-12

FIGURE 9. VCO Capacitor



TL/F/5182-13

FIGURE 10. VCO Capacitor Value for Disk Data Rates

Loop Filter

The input current into the Buffer Amplifier is offset by a matched current out of the Charge Pump, and even so is much less than the switching current in or out of the Charge Pump. It can therefore be assumed that all the Charge Pump switching current goes into the Loop Filter components R_{LF1} and C_{LF1} and C_{LF2} . The tolerance of these components should be the same as R_{RATE} and R_{BOOST} , and will determine the overall loop gain variation. The three components connected to the Charge Pump output are shown in Figure 11. Note the return current goes to analog GND, which should be electrically very close to the GND pin itself.

The value of capacitor C_{LF1} basically determines loop stability—the larger the value the longer the loop takes to respond to an input change. If C_{LF1} is too small, the loop will track any jitter on the ENCODED DATA input and the VCO output will follow this jitter, which is undesirable. The value of C_{LF1} should therefore be large enough so that the PLL is fairly immune to phase jitter but not large enough that the loop won't respond to longer term data rate changes that occur on the disk drive.

The damping resistor R_{LF1} is required to damp any oscillation on the VCO input that would otherwise occur due to step function changes on the input. A value of R_{LF1} that would give a phase margin of around 45 degrees would be a reasonable starting point.

The main function of the capacitor C_{LF2} is to integrate the effects of the VCO frequency on the VCO input voltage. Typically its value will be about one tenth of C_{LF1} .

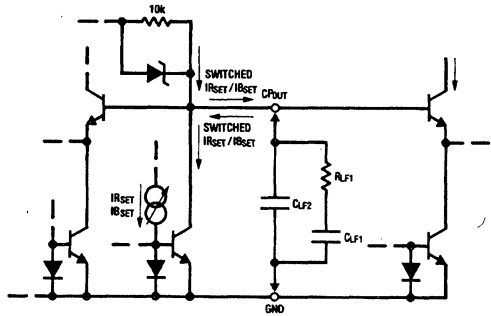
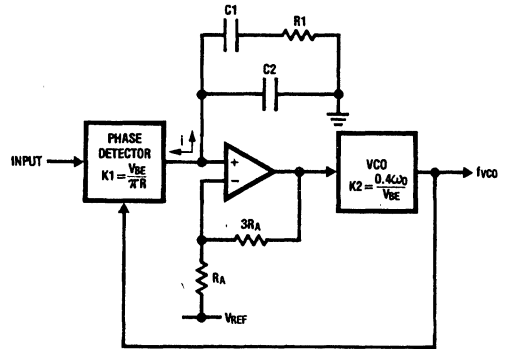


FIGURE 11. Charge Pump Out

TL/F/5182-14



TL/F/5182-15

FIGURE 12. Loop Response Components

Figure 12 shows the relevant phase-locked-loop blocks that determine system response, namely the Phase Detector, Filter/Buffer Amplifier, and VCO. The Phase Detector (Phase Comparator and Charge Pump) produces an aggregate output current i which is proportional to the phase difference between the input signal and the VCO signal. The constant (K_1) is $V_{BE}/\pi R$ amps per radian. R is either R_{RATE} or $R_{RATE} \parallel R_{BOOST}$. This aggregate current feeds into or out of the filter impedance (Z), producing a voltage to the VCO that regulates the VCO frequency. The VCO gain constant is $0.4 \omega_{VCO}/V_{BE}$ radians per second per volt. Under steady state conditions, i will be zero and there will be no phase difference between the input signal and the VCO. Any change of input signal will produce a change in VCO frequency that is determined by the loop gain equation. This equation is determined from the gain constants K_1 , A and K_2 and the filter v/i response.

The impedance Z of the filter is:

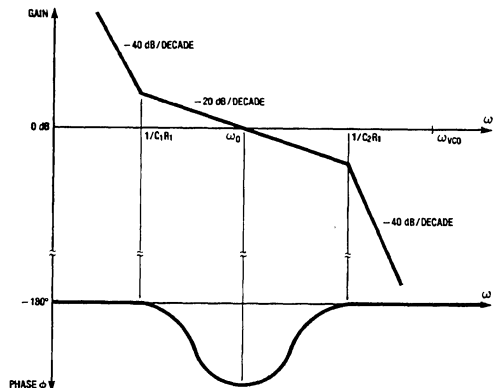
$$\frac{1}{sC_2} \parallel \left(\frac{1}{sC_1} + R_1 \right) = \frac{1 + sC_1R_1}{sC_1 \left(1 + \frac{C_2}{C_1} + sC_2R_1 \right)}$$

If $C_2 \ll C_1$ then the impedance Z approximates to:

$$\frac{1 + sC_1R_1}{sC_1 (1 + sC_2R_1)}$$

The overall loop gain is then $G(s) = \frac{K_1AK_2}{s} \times \frac{1 + sC_1R_1}{sC_1(1 + sC_2R_1)}$

The desired Bode plot of gain and phase is shown in *Figure 13*, with -20dB/decade slope at ω_0 for stability at unity gain.



TL/F/5182-16

FIGURE 13. Bode Plot of Loop Response

If the point of inflexion of the phase curve is at ω_0 , (the loop natural frequency and therefore the closed loop bandwidth), then it can be shown that for a phase margin ϕ ,

$$C_2R_1 = \frac{1 - \sin \phi}{\omega_0 \cos \phi} \text{ sec}$$

$$C_1R_1 = \frac{1}{\omega_0^2 C_2R_1} \text{ sec}$$

$$\text{and } C_1 = \frac{K_1 A K_2}{\omega_0^2} \times \frac{1 + \omega_0 C_1 R_1}{1 + \omega_0 C_2 R_1} \text{ F}$$

As an example, if we want the PLL to lock-on within two bytes of preamble in the high tracking rate mode, and the disk data rate is 5Mbits/sec, or one bit every 200ns.

(Thus $f_{VCO} = 10\text{MHz}$)

time to lock = $16 \times 0.2\mu\text{s} = 3.2\mu\text{s}$

Closed loop bandwidth $f_0 > (0.3/3.2) \text{ MHz}$ or about 100kHz

(the factor 0.3 is a rule of thumb guideline derived from the product of rise time and bandwidth).

Select a bandwidth $f_0 = 200\text{kHz}$ so that $\omega_0 = 2\pi \times 200\text{kHz}$ (giving a ratio of $f_{VCO} / f_0 = 50$)

Select a phase margin ϕ between 30° and 70° for stability. Choose $\phi = 45^\circ$ for optimum response

$$\text{Then } C_2R_1 = \frac{(1 - \sin 45^\circ)}{2\pi \times 200 \times 10^3 \times \cos 45^\circ} = 0.33 \times 10^{-6} \text{ sec}$$

$$\text{and } C_1R_1 = \frac{1}{(2\pi \times 200 \times 10^3)^2 \times 0.33 \times 10^{-6}} = 1.92 \times 10^{-6} \text{ sec}$$

To determine C_1 , we need to know K_1 , A and K_2 .

$$K_1 = \frac{V_{BE}}{\pi R} \text{ amps per radian}$$

In the high tracking rate, $R = 1.1\text{k} \parallel 3.3\text{k} = 825\Omega$ for our example from the Charge Pump calculations

$$\text{So } K_1 = \frac{V_{BE}}{\pi \times 825} \text{ amps/radian}$$

the Buffer Amplifier gain A is internally set to 4.0

$$K_2 = \frac{0.4\omega_{VCO}}{V_{BE}} \text{ radians per sec per volt}$$

$$K_2 = \frac{0.4 \times 2\pi \times 10^7}{V_{BE}} \text{ radians per sec per volt}$$

$$\text{so } C_1 = \frac{V_{BE}}{\pi \times 825} \times 4.0 \times \frac{0.4 \times 2\pi \times 10^7}{V_{BE} \times (2\pi \times 200 \times 10^3)^2} \times$$

$$\frac{1 + (2\pi \times 200 \times 10^3 \times 1.92 \times 10^{-6})}{1 + (2\pi \times 200 \times 10^3 \times 0.33 \times 10^{-6})} \text{ F}$$

The V_{BE} in the K_1 equation cancels with the V_{BE} in the K_2 equation provided good matching is maintained on the DP8460.

Thus $C_1 = 5.923 \times 10^{-8}\text{F}$. Select C_1 to be $0.056\mu\text{F}$

$$\therefore R_1 = \frac{1.92 \times 10^{-6}}{56000 \times 10^{-12}} \Omega = 34.28\Omega. \text{ Select } R_1 = 33\Omega$$

$$\therefore C_2 = \frac{0.33 \times 10^{-6}}{33} \text{ F} = 10^{-8}\text{F} = 0.01\mu\text{F}. \text{ Select } C_2 = 0.01\mu\text{F}$$

The calculated values are only a guide, the user should then empirically test the loop and determine stability, lock-on time, jitter tolerance, etc.

Note that capacitor C_2 affects the amount by which the Charge Pump switching current affects the filter voltage. Obviously as C_2 is increased in value ripple will decrease, but the closer the -40dB/decade slope gets to ω_0 on the Bode plot the more unstable the loop will be. Thus if C_2 is made too large the loop will oscillate.

Resistor R_1 determines where the low-frequency end -40dB/decade slope changes into the -20dB/decade slope. The wider the -20dB/decade slope is around unity gain, the more stable the loop becomes. If R_1 is too large it will reduce the impact of C_1 , while too small a value will increase instability. The capacitor C_1 strongly effects the response of the loop. Too high a value will slow down the response time, but make it less prone to jitter or frequency shift whereas too low a value will improve response time while tending to react to jitter.

Other filter combinations may be used, other than R_{LF1} in series with C_{LF1} , all in parallel with C_{LF2} . For example the filter shown in Figure 14 will also perform similarly, and in fact for some systems it will yield superior performance.

DIGITAL CONNECTIONS TO THE DP8460

Figure 17 shows a connection diagram for the DP8460 in a typical application. All logic inputs and outputs are TTL compatible as shown in Figures 15 and 16. The VCO CLOCK output is 74AS compatible and can therefore drive up to 40 74AS (or 74F) inputs, or 10 74S inputs, or 100 74ALS inputs, or 50 of 74LS inputs. All other outputs are 74ALS compatible and so will drive up to 16 74AS inputs, or 4 74S inputs, or 40 74ALS inputs or 20 74LS inputs. All inputs are 74ALS compatible and therefore can be driven easily from any 74 series devices. The raw MFM from the pulse detector in the drive is connected to the ENCODED DATA input. The DELAY DISABLE input determines whether attempting lock-on will begin immediately after READ GATE is set or after 2 bytes. Typically in a hard-sectored drive, READ GATE is set active as the sector pulse appears, meaning a new sector is about to pass under the head. Normally the preamble pattern does not begin immediately, because gap bytes from the preceding sector usually extend just beyond the sector pulse. Allowing 2 bytes to pass after the sector pulse helps ensure that the PLL will begin locking on to preamble, and will not be chasing non-symmetrical gap bits. Attempting to lock-on to a fixed $\dots 1010\dots$ preamble pattern speeds up lock-on, and after another two bytes the PLL will nominally have locked-on. Thus DELAY DISABLE should be set low for this kind of disk drive.

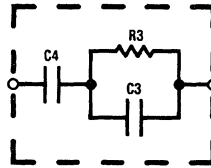


FIGURE 14. Alternate Loop Filter Configuration

TL/F/5182-17

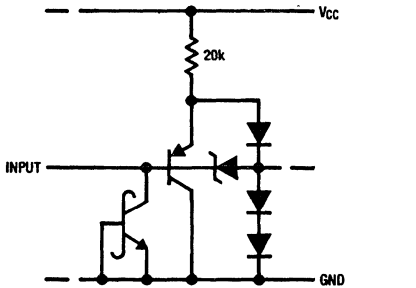


FIGURE 15. Logic Inputs

TL/F/5182-18

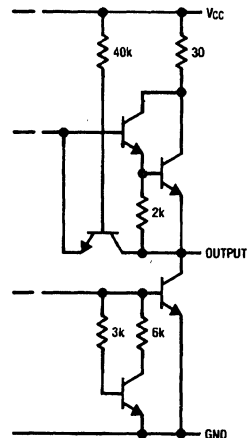


FIGURE 16. Logic Outputs

TL/F/5182-19

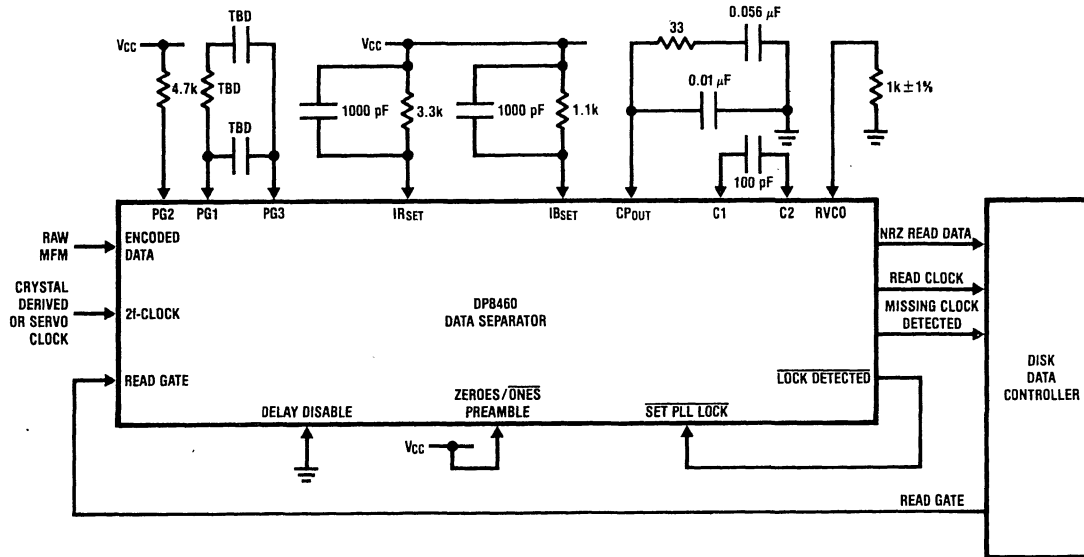


FIGURE 17. Typical Connection to DP8460 for:
 1) MFM Data Input, 5Mbit/sec Data Rate
 2) 32 Bit Delay to Enable
 3) All Zeroes (NRZ) Preamble

TL/F/5182-20

For soft sector drives, the controller normally will not wait for the index pulse before it attempts lock-on, so that READ GATE may go active at any time. Chances are the head will not be over a preamble field and therefore there is no need to wait 2 bytes before attempting lock-on. DELAY DISABLE can therefore be set high. If a non-preamble field is passing by as READ GATE goes active, the DP8460 will not indicate lock, and no data decoding will occur nor will MISSING CLOCK DETECTED go active. Normally, if lock-on has not been achieved after a certain time limit, the controller will de-activate READ GATE and then try again.

For MFM encoded disk drives, the LOCK DETECTED output will be connected back to the SET PLL LOCK input. As the PLL achieves lock-on, the DP8460 will automatically switch to the slower tracking rate and decoded data will appear at the NRZ READ DATA output. Also the READ CLOCK output will switch from half the 2f-clock frequency to the disk data rate frequency. If a delay is required before the changeover occurs, a time delay may be inserted between the two pins.

Some drives have an all-ONES data preamble instead of all-ZEROES and the DP8460 must be set to the type being used before it can properly decode data. The ZEROES/ONES PREAMBLE input selects which preamble type the chip is to lock-on to.

If the drive uses a run-length-limited (RLL) code such as '2, 7', instead of MFM, the phase-locked-loop function of the DP8460 may still be used. Figure 18 shows how the DP8460 may be connected to a RLL ENDEC circuit. The RLL ENDEC performs encoding of NRZ data to RLL encoded data, and RLL encoded data back to NRZ data. The RLL ENDEC can use the SYNCHRONIZED DATA output of the DP8460 along with VCO CLOCK to lock-on to the preamble and then decode data. Once lock-on has been detected, the RLL ENDEC can set the SET PLL LOCK input of the DP8460 low so that the tracking rate can be changed.

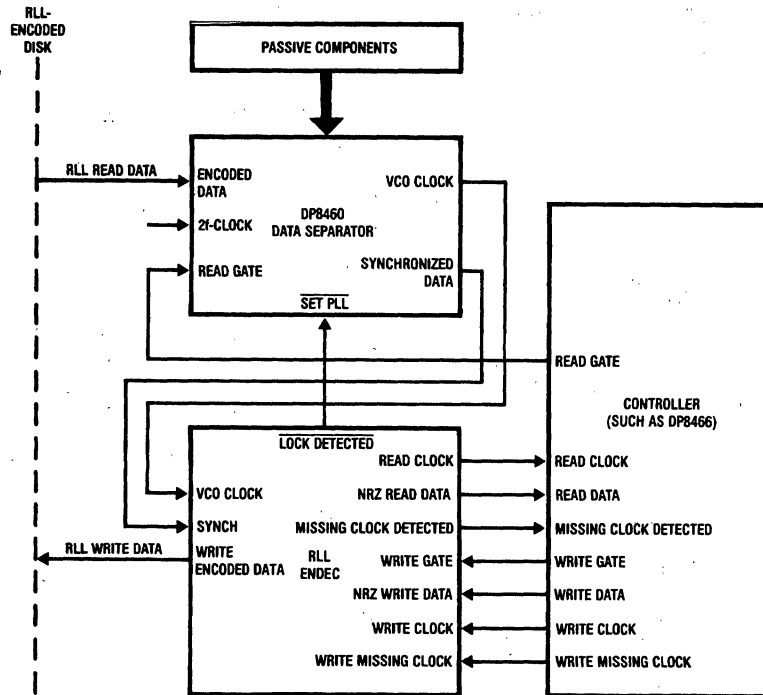


FIGURE 18. DP8460 with Run-Length-Limited (RLL) Codes

TL/F/5182-21

APPLICATIONS OF THE DP8460 DATA SEPARATOR

The DP8460 is the first integrated circuit to place on one chip a PLL with features that offer the improved speed and reliability required by the disk industry. Not only does the chip simplify disk system design, but also provides fast lock-on to the incoming preamble. Once locked on, the loop is set into a more stable mode. This inherent loop stability allows for a sizeable amount of jitter on the data stream, such as is encountered in many disk systems. Once in the stable tracking rate, the SYNCHRONIZED DATA output represents the incoming ENCODED DATA and is synchronous with VCO CLOCK. If the disk is MFm encoded, then the chip can decode the synchronized data into NRZ READ DATA and READ CLOCK. These are available as outputs from the chip allowing the NRZ READ DATA to be deserialized using the READ CLOCK.

The DP8460 is capable of operating at up to 25Mbits/sec data rates and so is compatible with a wide assortment of disk drives. The faster data rates of the 8-inch and 14-inch disk drives will mandate the selection of either the

DP8460-3 or -2 parts with their narrower window margins on the incoming data stream. This will also be the case when 5¼-inch drives achieve higher data rates. Some 8-inch and 14-inch disk drives incorporate the functions of the DP8460, but use many discrete ICs. In these cases, replacing these components with the DP8460 will offer reduced P.C. board area, lower cost, and improved performance while simplifying circuit testing.

Most 5¼-inch and many 8-inch and 14-inch disk drives manufactured at present do not incorporate any of the functions of the DP8460. This is so primarily because the PLL function is difficult to design and implement, and requires circuitry which covers a large area of the printed circuit card. This is undesirable both from the drive size aspect and from the cost aspect (the cost includes soldering, testing, and adjusting the components). Consequently, most smaller disk drives output MFm encoded data so that the phase-locked-loop and data separation have to be performed by the controller. The DP8460 will therefore replace these functions in controller designs, as shown in *Figure 19*.

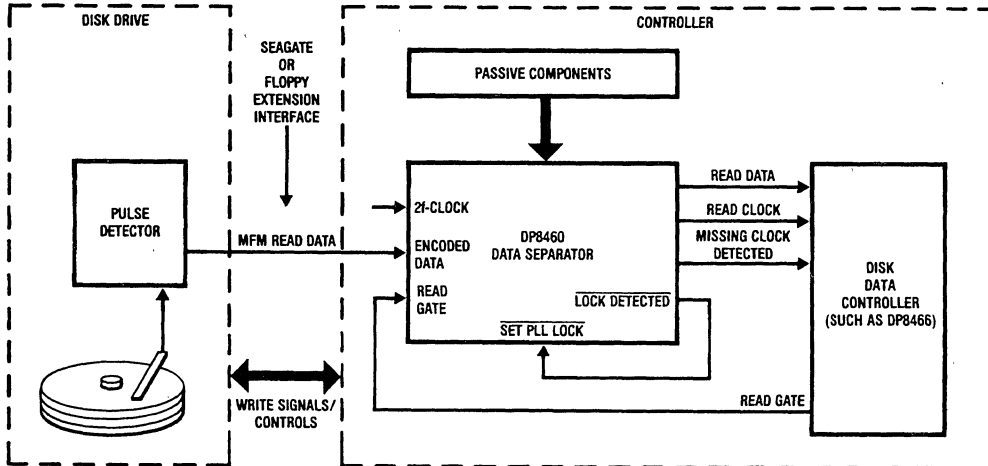


FIGURE 19. DP8460 in the Controller

TL/F/5182-22

System design criteria may now change because the DP8460 is a one-chip solution, requiring only a few external passive components with fixed values. It operates from a +5V supply, consumes about 0.5W, and is housed in a narrow 24-pin package. The circuitry has been designed so that the external resistors and capacitors need not be adjustable; the user chooses the values according to the disk drive requirements. Once selected, they will be fixed for that particular drive type. These features make it possible to transfer these functions to the disk drive, as shown in *Figure 20*. Apart from a slight increase in board area, the advantages outweigh the disadvantages. First, the components selected are fixed for each type of drive and this facilitates the problem of interchangeability of drives. At present, controllers are adjusted to function with each specific drive; with the DP8460 in the drive, component adjustment will no longer be required. Second there is often a problem of reliability of data transfer. Because the MFM data is clock encoded, this signal is susceptible to noise, bit shift, etc. Soft errors will sometimes occur when the incoming disk data bit posi-

tion is outside the Pulse Gate window as it is being synchronized to the VCO clock in the phase-locked-loop. Obviously, the nearer the PLL is to the MFM source, the less chance there is that errors will occur. Thus placing the DP8460 in the drive will increase the reliability of data transfer within the system.

A third advantage is data rate upgrading. Most 5¼-inch drives have 5Mbit/sec data rate because the early drives were made with this data rate. This meant the controllers had to be designed with PLLs which operate at this data rate. It is therefore difficult for drive manufacturers to introduce new drives that are not compatible with existing controllers. Since no new standard data rate has emerged, they must continue to produce drives at this data rate to be compatible with the controllers on the market. With the DP8460 in the drive, and its associated components set for the drive's data rate, it no longer becomes a problem to increase the data rate, assuming the controllers digital circuitry can accommodate the change. This will allow the manufacturers to increase the bit density and therefore the capacity of their drives.

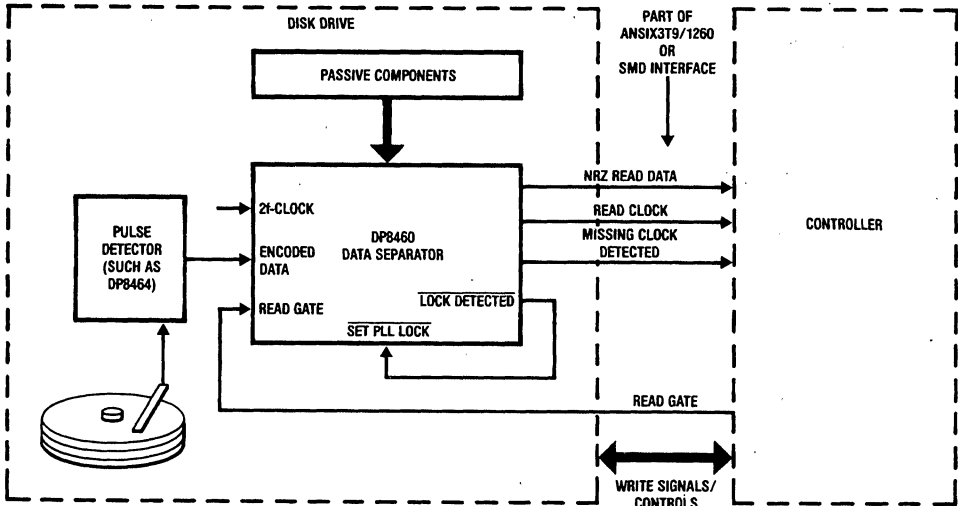


FIGURE 20. DP8460 in the Disk Drive

TL/F/5182-23

DP8464 Disk Pulse Detector

General Description

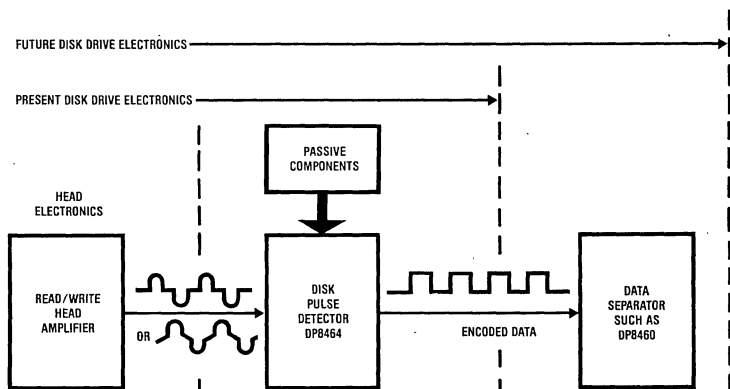
The DP8464 disk pulse detector utilizes analog and digital circuitry to detect amplitude peaks of the signal received from the read/write amplifier fitted in the heads of disk drives. The DP8464 produces a TTL compatible output which, on the positive edge, indicates a signal peak. Electrically, these peaks correspond to 1s or flux reversals on the magnetic medium. The signal received when reading a disk is therefore a series of pulses which alternate in polarity. The disk pulse detector must accurately determine the time positions of these peaks. This task is complicated by variable pulse amplitudes depending on the media type, head position, head type, and read/write amplifier circuit gain. Additionally, as the bit density on the disk increases the amplitude decreases and significant bit interaction occurs resulting in pulse distortion.

The graph below shows how pulse amplitude varies with the number of bits per inch (or recording density). The predominant disk applications are associated with the first two regions on the graph, regions 1 and 2. Typical waveforms received by the pulse detector for regions 1 and 2 operation are shown next to the graph. A region 1 signal is characterized by the waveform returning to the baseline between pulses. A region 2 waveform will go from a tendency to return to the baseline (called shouldering) to almost sinusoidal at the higher frequencies.

The disk pulse detector is fabricated using the advanced Schottky process, and has been designed to function with data rates up to 25 megabits/second. The DP8464 is housed in a standard narrow 24-pin package. Normally, it will be fitted in the disk drive, and its output may be directly connected to the DP8460 data separator.

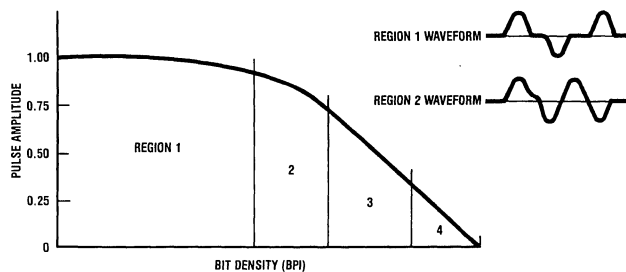
Features

- Connects directly with the disk head read/write amplifier
- Wide input signal amplitude range—from 20 mVpp to 600 mVpp differential
- Data rates up to 25 Mbits/sec
- On-chip wideband differential AGC amplifier, differentiator, comparator gating circuitry, output pulse generator
- Adjustable comparator threshold
- Selectable attack and differentiator capacitors
- Inputs and outputs TTL compatible
- Output may connect directly to the DP8460 data separator
- Standard narrow 24-pin dual-in-line package
- Standard supply: 12V ± 10%



Pulse Amplitude vs Bit Density with Typical Waveforms

TL/F/5283-1



TL/F/5283-2

Functional Description

DETECTOR OPERATION

Region 1 is the high resolution area characterized by a large spread between flux reversals and a definite return to baseline (no signal) between these peaks. Pulses of this type are predominantly found in systems which use thin film heads, plated media and systems which utilize run-length-limited coding techniques (like the 2,7 code) which spread the distance between flux reversals.

The main circuit blocks of the DP8464 are shown in *Figure 1*. The output from the read/write amplifier is fed directly to the amplifier input of the DP8464. This amplifier is a high bandwidth amplifier with automatic gain control (AGC). The amplifier's output voltage is fed back via an external filter to an internal fullwave rectifier and compared against the external voltage on the V_{REF} pin. The AGC circuit adjusts the gain of the amplifier to make the peak to peak differential analog output four times the voltage on V_{REF} . The circuit is designed for a V_{REF} of 1V which produces constant 4V peak to peak differential output for differential input signals ranging from 20 mVpp to 300 mVpp.

The peak detection is performed by feeding the output of the wideband amplifier through an external filter to the differentiator. The differentiator output changes state when the input pulse changes direction, generally this will be at the peaks. However, if the signal exhibits shouldering (the tendency to return to the baseline) as seen in region 1 and the upper part of region 2, the differentiator will also respond to noise near the baseline. To avoid this, the signal is also fed to a comparator which is used to define a level around the baseline. Data detection is prevented when the input is less than this level. The threshold for this comparator is externally set via the SET THRESHOLD pin. The comparator output feeds the hold input of the differentiator. The output of the differentiator then drives the bi-directional one-shot. A 4 Vpp differential output voltage will produce a 1V fullwave rectified signal at the input of the comparator. Therefore, if the voltage on the SET THRESHOLD pin is 0.3V, the input must be larger than ± 300 mV before the differentiator is allowed to trigger the one-shot. This comparator circuit thus acts as a gating channel to prevent any noise near the baseline from con-

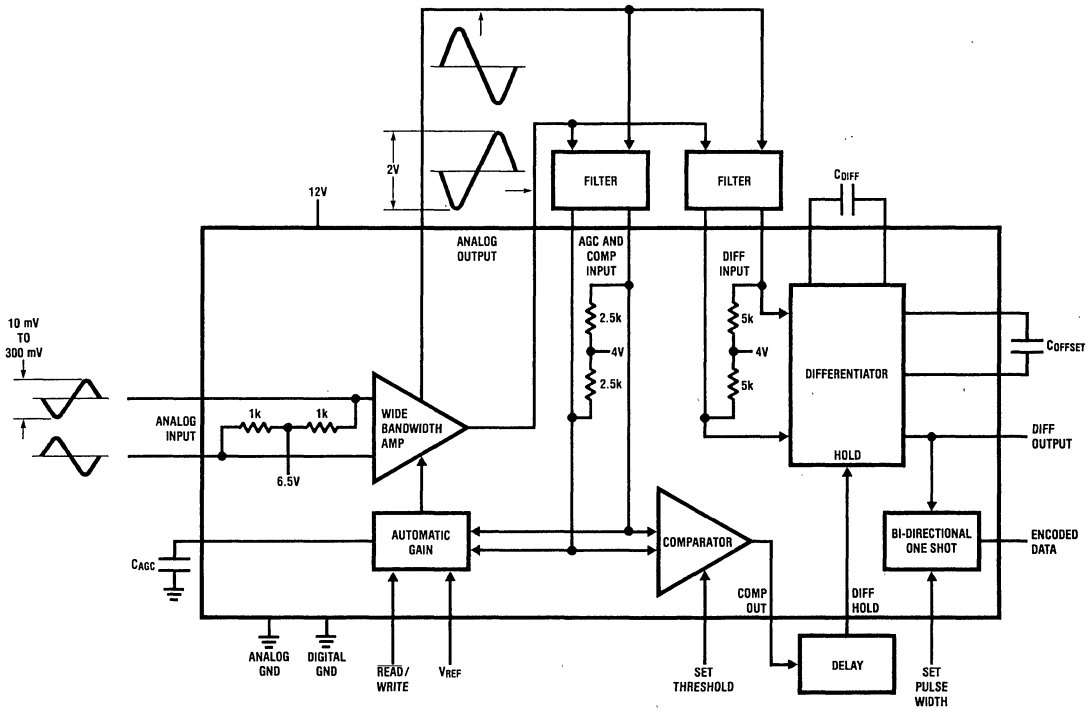
taminating the data. The diff output, encoded data, and comp out are all standard TTL outputs. The pulse width of the encoded data can be adjusted from 20 ns to 200 ns via the set pulse width.

The timing of the gating channel with respect to the differentiator output is critical. If the delay through the comparator is longer than the delay through the differentiator, then the window is not centered around the peak of the waveform and the circuit will not perform optimally. The correct operation is to have the differentiator output switch in the middle of the comparator output waveform. Often, to make the differentiator less sensitive to high frequency noise, an RLC filter will be used in place of the differentiator capacitor. This will increase the delay time through the differentiator. To cancel out the effect of this delay, an external delay can be inserted between comp out and diff hold.

Offset of the differentiator is critical to the performance of the circuit. Offset will cause "pulse pairing" which simply means that every other pulse is delayed. This happens because a positive offset will delay all the positive pulses. This obviously will ruin the encoded data. The DP8464 provides two C_{OFFSET} pins for an external capacitor. This capacitor will bandlimit the differential signal going into offset adjust circuitry in the differentiator. In this way, the differentiator is actively corrected to eliminate the initial offset and drift with temperature and time.

The wideband amplifier output is provided to allow the use of external filters to the differentiator and to the AGC circuit. The filter to the differentiator enables the user to limit the bandwidth for noise considerations. The filter to the AGC circuit allows the user to insert a lead network to prevent the AGC amplifier from responding to frequency induced amplitude changes.

The DP8464 has a READ/WRITE control pin which is used to minimize the effect on the AGC amplifier of a write-to-read transition. This allows a reduction in the size of the track gap on disk. This pin may be connected to the WRITE GATE output of the DP8466 disk data controller.



TLF/5283.3

FIGURE 1. Pulse Detector Block Diagram

DP8466 Disk Data Controller

General Description

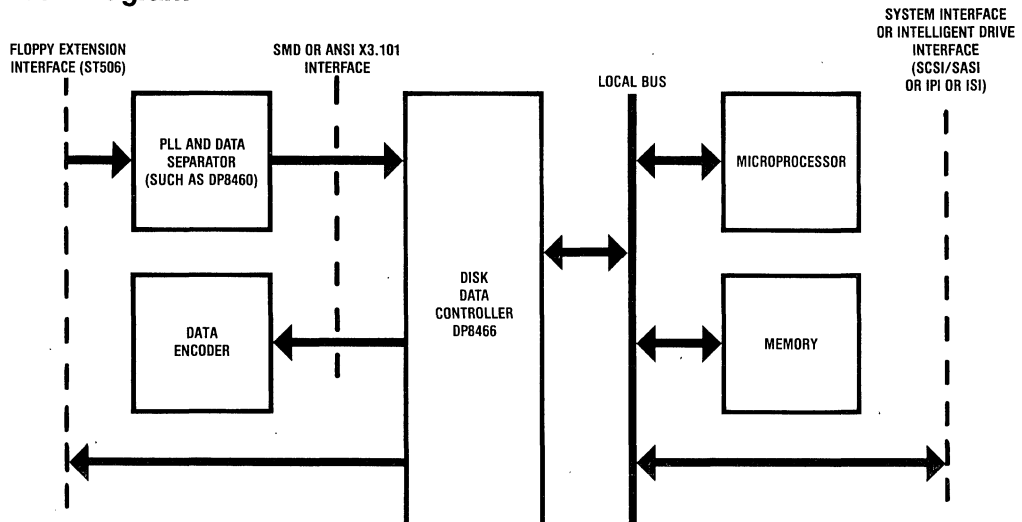
The disk data controller (DDC) performs many of the functions in the data path electronics of either disk controllers or intelligent disk drives. It interfaces between serial data on the disk side and the memory/microprocessor bus on the system side. The primary function of the chip is to correctly identify the selected sector on disk and then transfer the sector's data to or from memory, utilizing a 32-byte (16-word) FIFO buffer with optional DMA control. The 48-pin chip is fabricated using the M²CMOSTM process, which allows complex functions to be implemented with high operating speeds and modest power consumption. Internal gate delays of 2 ns allow the DDC to function with data rates over 24 Mbits/sec, enabling it to be used with all sizes of Winchester and floppy disk drives.

The disk side of the DDC interfaces directly with drives compatible with the ESDI, SMD or ANSI X3.101 interfaces. If the DDC is part of a controller that interfaces directly to the ST506 (floppy extension interface), then the DP8460 data separator may be used and its signals will connect directly to the DDC. The DDC may be part of an intelligent disk drive that has SCSI (SASI) or IPI or ISI compatible interfaces.

Features

- Useable with Winchester, floppy, optical and vertically recorded drives
- Disk data rates up to 24 Mbits/sec
- Meets requirements of all standard disk drive interfaces
- User programmable format
- Compatible with all disk drive sizes, fixed or removable
- Compatible with hard and soft sectored drives
- Single or multiple sector operation
- Independent header and data operations
- Internal CRC or ECC, or external ECC, for header and data
- Internal ECC has programmable polynomial and correction span
- Configurable for disk formatting
- System side interfaces to memory and microprocessor
- Easily controlled by popular 8-bit or 16-bit microprocessors
- 8 or 16-bit wide memory transfers
- Internal data buffering with 32-byte FIFO
- Single channel 32-bit or dual channel 16-bit DMA controller
- Powerful data path diagnostics
- Low power consumption at lower data rates and standby
- Single +5V power supply
- Standard 48-pin DIP

Block Diagram



TLI/F5282-1

The system side of the DDC may interface directly to the main system bus, or the local bus of a larger system. The DDC has a 16-bit I/O bus and associated microprocessor/DMA handshake signals. The I/O bus is used both for disk data transfers to or from memory (user-selectable for 8 or 16 data bits) and for microprocessor access. The microprocessor may have a multiplexed or separate address and data bus. The DDC has two DMA channels available for memory transfer operations. In a typical low-end system the DDC connects directly to the main system bus, and only one DMA channel is required to output memory addresses. The on-chip DMA issues the address on the I/O bus, followed by the data to be transferred between the DDC and memory. The DDC has variable burst transfer length capability that allows microprocessor usage of the bus during transfer operations. The DDC supports a second mode of DMA capability which is ideal for intelligent disk drives or higher-end systems that use a buffer memory. One DMA channel controls disk-memory transfers, and the second controls memory-system transfers.

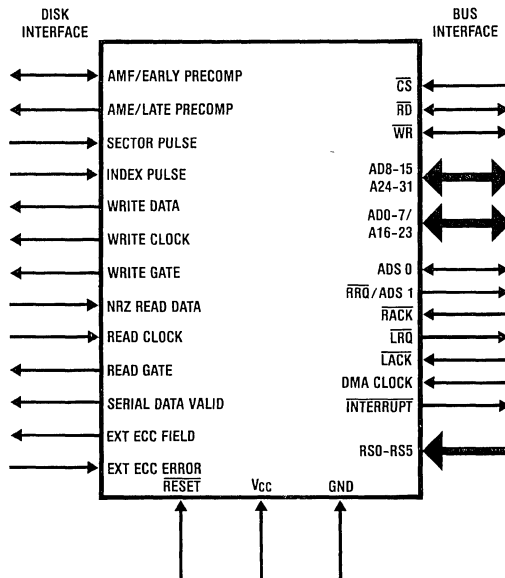
To be compatible with the differing needs of these disk drives, the DDC has been configured so that the format

and mode of operation are user programmable. The user selects the length and pattern of the preamble, address mark (if required), synch, postamble, and gap of both the ID and data segments of the sector. At system initialization, the microprocessor loads these parameters into the parameter RAM of the DDC. For normal transactions such as reading from or writing to the disk, the desired ID bytes must first be loaded into the DDC, followed by the disk drive command. The DDC can also be configured to format disks.

Extensive diagnostic and interrogation features are provided on-chip. CRC or ECC calculations are performed on both the ID and data segments that pass through the DDC. The ECC code may be an internally generated 32-bit fully programmable ECC code or up to 15 bytes of externally generated ECC code. The DDC contains status and error registers that can be accessed by the microprocessor.

Control functions not in the data path electronics have been omitted to allow for versatility in interfacing to different drive requirements. The drive control signals may be provided by either a dedicated microcontroller or a microprocessor I/O port.

DDC Connection Diagram (48 pins)



TL/F/5282-2



Section 11 Frequency Synthesis



DEVICE	DESCRIPTION	PAGE NUMBER
DS8906	AM/FM Digital Phase-Locked Loop Frequency Synthesizer	11-4
DS8907	AM/FM Digital Phase-Locked Loop Frequency Synthesizer	11-10
DS8908	AM/FM Digital Phase-Locked Loop Frequency Synthesizer	11-16
DS8614	130/225 MHz Low Power Dual Modulus Prescalers	11-23
DS8615	130/225 MHz Low Power Dual Modulus Prescalers	11-23
DS8616	130/225 MHz Low Power Dual Modulus Prescalers	11-23
DS8617	130/225 MHz Low Power Dual Modulus Prescalers	11-23
DS8626	120 MHz Divide-by-40 Prescaler	11-27
DS8629	120 MHz Divide-by-100 Prescaler	11-27
DS8627	130/225 MHz Low Power Prescalers	11-30
DS8628	130/225 MHz Low Power Prescalers	11-30
DS8621	275 MHz/1.2 GHz VHF/UHF Prescaler	11-33
DS8622	500 MHz/1.2 GHz Dual Modulus VHF/UHF Prescaler	11-36
AN-335	Digital PLL Synthesis	11-40

Frequency Synthesizers Selection Guide

Product Type	Frequency Bands	Power (mA)	Tuning Resolution	Page No.
PLL FREQUENCY SYNTHESIZERS				
DS8906	AM/FM	160	500 Hz/12.5 kHz	11-4
DS8907	AM/FM	160	10 kHz/25 kHz	11-10
DS8908	AM/FM	160	1 kHz, 9 kHz, 10 kHz, 20 kHz	11-16
AN-335 Digital PLL Synthesis				11-40

Product Type	Divide Modulus	Power (mA)	f _{MAX}	Page No.
HIGH FREQUENCY PRESCALERS				
Single (Fixed) Modulus Dividers				
DS8626	÷ 40	125	120 MHz	11-27
DS8627	÷ 24	7/10	130/225 MHz	11-30
DS8628	÷ 20	7/10	130/225 MHz	11-30
DS8629	÷ 100	135	120 MHz	11-27
DS8621	÷ 64, ÷ 256	32	275 MHz, 1.2 GHz	11-33
Dual-Modulus Dividers				
DS8614	÷ 20/21	7/10	130/225 MHz	11-23
DS8615	÷ 32/33	7/10	130/225 MHz	11-23
DS8616	÷ 40/41	7/10	130/225 MHz	11-23
DS8617	÷ 64/65	7/10	130/225 MHz	11-23
DS8622	÷ 126/128, ÷ 252/256	32	550 MHz, 1.2 GHz	11-36

DS8906 AM/FM Digital Phase-Locked Loop Synthesizer

General Description

The DS8906 is a PLL synthesizer designed specifically for use in AM/FM radios. It contains the reference oscillator, a phase comparator, a charge pump, a 120 MHz ECL/ I^2L dual modulus programmable divider, and a 20-bit shift register/latch for serial data entry. The device is designed to operate with a serial data controller generating the necessary division codes for each frequency, and logic state information for radio function inputs/outputs.

The Colpitts reference oscillator for the PLL operates at 4 MHz. A chain of dividers is used to generate a 500 kHz clock signal for the external controller. Additional dividers generate a 12.5 kHz reference signal for FM and a 500 Hz reference signal for AM/SW. One of these reference signals is selected by the data from the controller for use by the phase comparator. Additional dividers are used to generate a 50 Hz timing signal used by the controller for "time-of-day".

Data is transferred between the frequency synthesizer and the controller via a 3 wire bus system. This consists of a data input line, an enable line, and a clock line. When the enable line is low, data can be shifted from the controller into the frequency synthesizer. When the enable line is transitioned from low to high, data entry is disabled and data present in the shift register is latched.

From the controller 22-bit data stream, the first 2 bits address the device permitting other devices to share the same bus. Of the remaining 20-bit data word, the next 14-bits are used for the PLL divide code. The remaining 6 bits are connected via latches to output pins. These 6 bits can be used to drive radio functions such as gain, mute, FM, AM, LW and SW only. These outputs are open collector. Bit 18 is used internally to select the AM or FM local oscillator input and to select between the 500 Hz and 12.5 kHz reference. A high level at bit 18 indicates FM and a low level indicates AM.

The PLL consists of a 14-bit programmable I^2L divider, an ECL phase comparator, an ECL dual modulus ($p/p + 1$) prescaler, and a high speed charge pump. The programmable divider divides by $(N+1)$, N being the number loaded into the shift register (bits 1-14 after address). It is clocked by the AM input via an $ECL \div 7/8$ prescaler, or through a $\div 63/64$ prescaler from the FM input. The AM input will work at frequencies up to 8 MHz, while the FM input works up to 120 MHz. The AM band is tuned with a frequency resolution of 500 Hz and the FM band is tuned with a resolution of 12.5 kHz. The buffered AM and FM inputs are self-biased and can be driven directly by the VCO thru a capacitor. The ECL phase comparator produces very accurate resolution of the phase difference between the input signal and the reference oscillator.

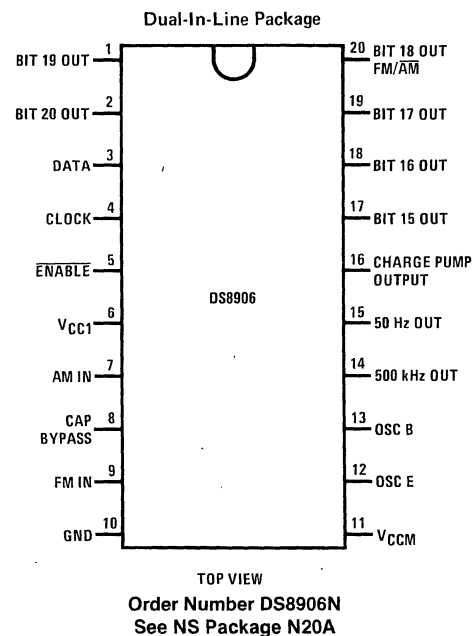
The high speed charge pump consists of a switchable constant current source (-0.3 mA) and a switchable constant current sink ($+0.3$ mA). If the VCO frequency is low, the charge pump will source current, and sink current if the VCO frequency is high.

A separate V_{CCM} pin (typically drawing 1.5 mA) powers the oscillator and reference chain to provide controller clocking frequencies when the balance of the PLL is powered down.

Features

- Uses inexpensive 4 MHz reference crystal
- F_{1N} capability greater than 120 MHz allows direct synthesis at FM frequencies
- FM resolution of 12.5 kHz allows usage of 10.7 MHz ceramic filter distribution.
- Serial data entry for simplified control.
- 50 Hz output for "time-of-day" reference with separate low power supply (V_{CCM}).
- 6-open collector buffered outputs for band switching and other radio functions.
- Separate AM and FM inputs. AM input has 15 mV (typical) hysteresis.

Connection Diagram



Absolute Maximum Ratings (Note 1)

Supply Voltage (V _{CC1})	7V
(V _{CCM})	7V
Input Voltage	7V
Output Voltage	7V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V _{CC}			
V _{CC1}	4.75	5.25	V
V _{CCM}	4.5	6.0	V
Temperature, T _A	0	70	°C

DC Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS		
V _{IH}	Logical "1" Input Voltage	2.1			V		
I _{IH}	Logical "1" Input Current	V _{IN} = V _{CC1}	0	10	μA		
V _{IL}	Logical "0" Input Voltage			0.7	V		
I _{IL}	Logical "0" Input Current	Data, Clock, and $\overline{\text{ENABLE}}$ Inputs, V _{IN} = 0V	-5	-25	μA		
I _{OH}	Logical "1" Output Current						
	All Bit Outputs, 50 Hz Output 500 kHz Output	V _{OH} = 5.25V V _{OH} = 2.4V, V _{CCM} = 4.5V		50	μA		
V _{OL}	Logical "0" Output Voltage						
	All Bit Outputs 50 Hz Output, 500 kHz Output	I _{OL} = 5 mA I _{OL} = 250 μA		0.5	V		
I _{CC1}	Supply Current (V _{CC1})	All Bit Outputs High	90	160	mA		
I _{CCM(STANDBY)}	V _{CCM} Supply Current	V _{CCM} = 6.0V, All Other Pins Open	1.5	4.0	mA		
I _{OUT}	Charge Pump Output Current	1.2V ≤ V _{OUT} ≤ V _{CCM} - 1.2V V _{CCM} ≤ 6.0V	Pump Up	-0.10	-0.30	-0.6	mA
			Pump Down	0.10	0.30	0.6	mA
			TRI-STATE [®]	0	±100	nA	
I _{CCM(OPERATE)}	V _{CCM} Supply Current	V _{CCM} = 6.0V, V _{CC1} = 5.25V, All Other Pins Open	2.5	6.0	mA		

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AC Electrical Characteristics V_{CC} = 5V, T_A = 25°C, t_r ≤ 10 ns, t_f ≤ 10 ns

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IN(MIN)} (F)	F _{IN} Minimum Signal Input	AM and FM Inputs, 0°C ≤ T _A ≤ 70°C	20	100	mV (rms)	
V _{IN(MAX)} (F)	F _{IN} Maximum Signal Input	AM and FM Inputs, 0°C ≤ T _A ≤ 70°C	1000	1500	mV (rms)	
F _{OPERATE}	Operating Frequency Range (Sine Wave Input)	V _{IN} = 100 mV rms 0°C ≤ T _A ≤ 70°C	AM	0.4	8	MHz
		FM	60	120	MHz	
R _{IN} (FM)	AC Input Resistance, FM	120 MHz, V _{IN} = 100 mV rms	300		Ω	
R _{IN} (AM)	AC Input Resistance, AM	2 MHz, V _{IN} = 100 mV rms	1000		Ω	
C _{IN}	Input Capacitance, FM and AM	V _{IN} = 120 MHz	3	6	10	pF
t _{EN1}	Minimum $\overline{\text{ENABLE}}$ High Pulse Width		625	1250	ns	
t _{EN0}	Minimum $\overline{\text{ENABLE}}$ Low Pulse Width		375	750	ns	
t _{CLKEN0}	Minimum Time Before $\overline{\text{ENABLE}}$ Goes Low that CLOCK Must be Low		-50	0	ns	
t _{EN0CLK}	Minimum Time After $\overline{\text{ENABLE}}$ Goes Low that CLOCK Must Remain Low		275	550	ns	
t _{CLKEN1}	Minimum Time Before $\overline{\text{ENABLE}}$ Goes High that Last Positive CLOCK Edge May Occur		300	600	ns	
t _{EN1CLK}	Minimum Time After $\overline{\text{ENABLE}}$ Goes High Before an Unused Positive CLOCK Edge May Occur		175	350	ns	

AC Electrical Characteristics (Continued) $V_{CC} = 5V, T_A = 25^\circ C, t_r \leq 10 ns, t_f \leq 10 ns$

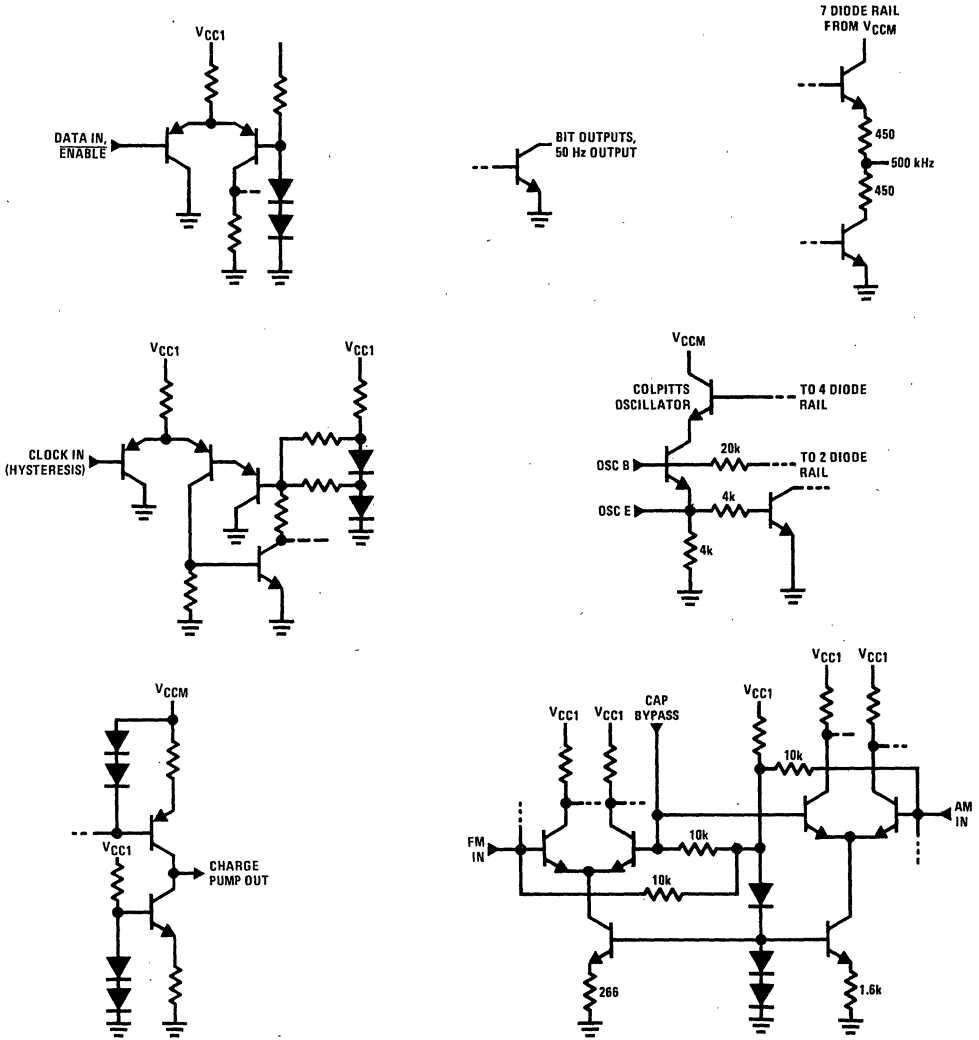
	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
t _{CLKH}	Minimum CLOCK High Pulse Width			275	550	ns
t _{CLKL}	Minimum CLOCK Low Pulse Width			400	800	ns
t _{DS}	Minimum DATA Setup Time, Minimum Time Before CLOCK that DATA Must be Valid			150	300	ns
t _{DH}	Minimum DATA Hold Time, Minimum Time After CLOCK that DATA Must Remain Valid			400	800	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

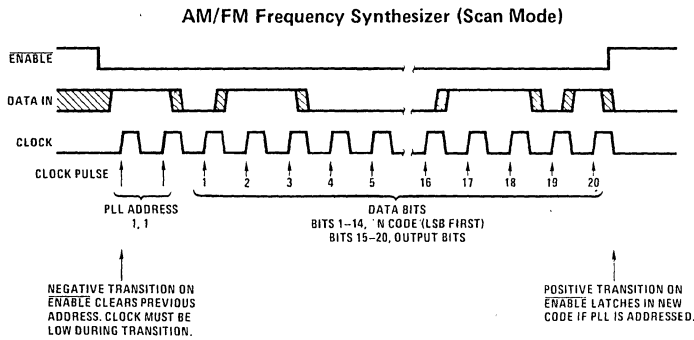
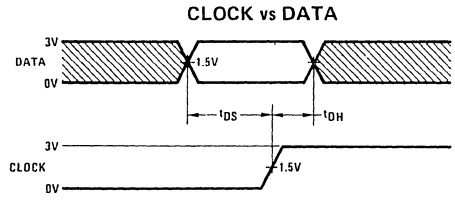
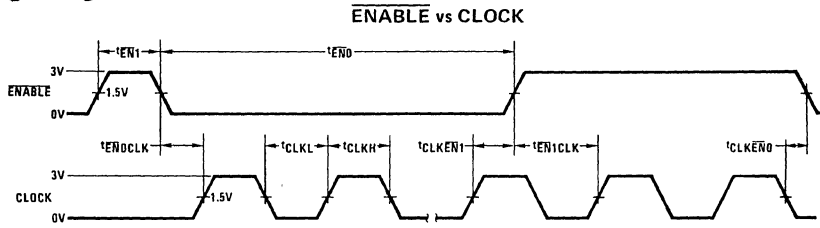
Note 2: Unless otherwise specified min/max limits apply across the 0°C to +70°C temperature range for the DS8906.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Schematic Diagrams (DS8906 AM/FM PLL Typical Input/Output Schematics)



Timing Diagrams *



* Timing diagrams are not drawn to scale. Scale within any one drawing may not be consistent, and intervals are defined positive as drawn.

SERIAL DATA ENTRY INTO THE DS8906

Serial information entry into the DS8906 is enabled by a low level on the ENABLE input. One binary bit is then accepted from the DATA input with each positive transition of the CLOCK input. The CLOCK input must be low for the specified time preceding and following the negative transition of the ENABLE input.

The first 2 bits accepted following the negative transition of the ENABLE input are interpreted as address. If these address bits are not 1,1, no further information will be accepted from the DATA inputs, and the internal data latches will not be changed when ENABLE returns high.

If these first 2 bits are 1,1, then all succeeding bits are accepted as data, and are shifted successively into the internal shift register as long as ENABLE remains low.

Any data bits preceding the 20th to last bit will be shifted out, and are thus irrelevant. Data bits are counted as any bits following 2 valid (1,1) address bits with the ENABLE low.

When the ENABLE input returns high, any further serial data input is inhibited. Upon this positive transition of the ENABLE, the data in the internal shift register is transferred into the internal data latches.

Note that until this time, the states of the internal data latches have remained unchanged.

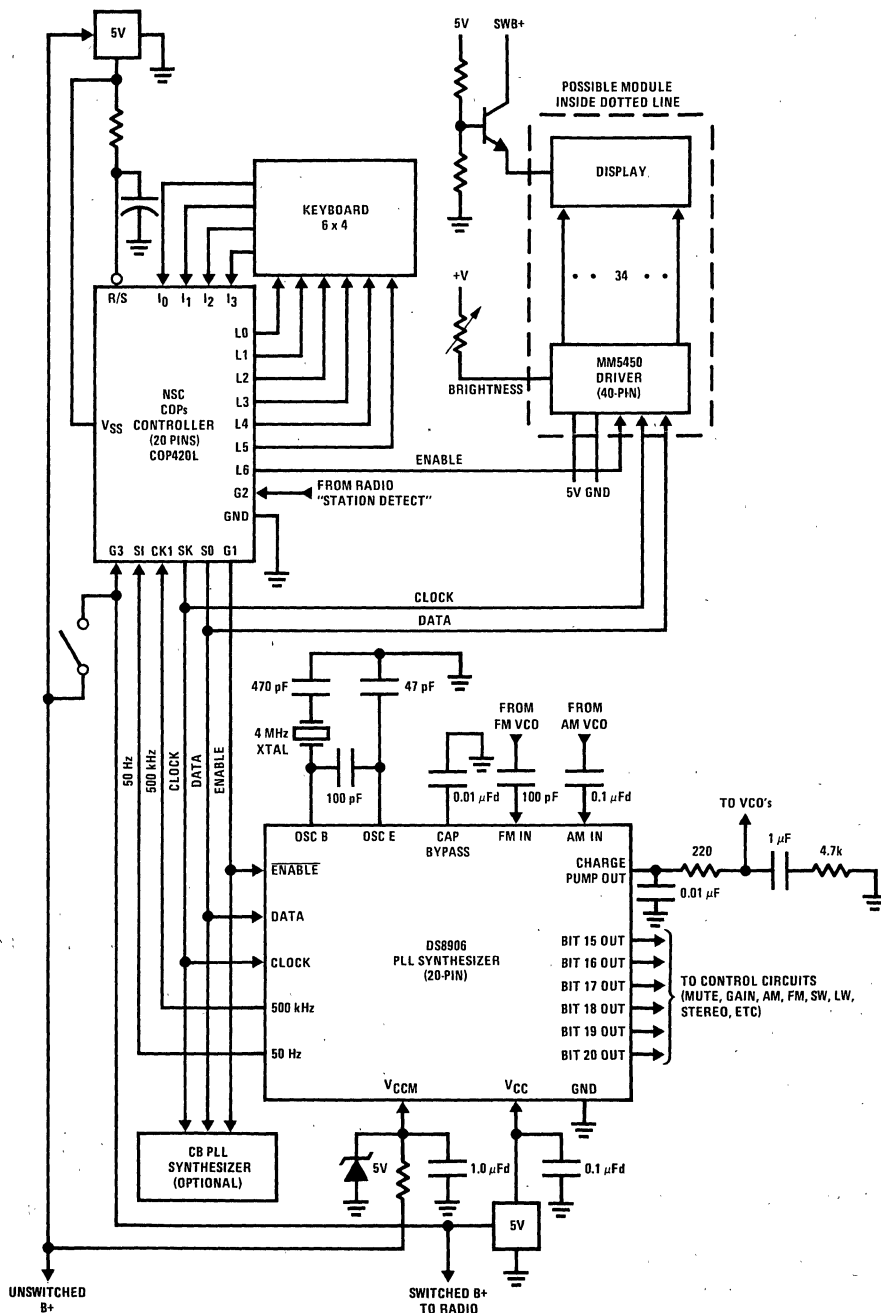
These data bits are interpreted as follows:

DATA BIT POSITION	DATA INTERPRETATION	
Last	Bit 20 Output (Pin 2)	
2nd to Last	Bit 19 Output (Pin 1)	
3rd to Last	Bit 18 Output (FM/AM) (Pin 20)	
4th to Last	Bit 17 Output (Pin 19)	
5th to Last	Bit 16 Output (Pin 18)	
6th to Last	Bit 15 Output (Pin 17)	
7th to Last	MSB of N (2 ¹³)	
8th to Last		(2 ¹²)
9th to Last		(2 ¹¹)
10th to Last		(2 ¹⁰)
11th to Last		(2 ⁹)
12th to Last		(2 ⁸)
13th to Last		(2 ⁷)
14th to Last		(2 ⁶)
15th to Last		(2 ⁵)
16th to Last		(2 ⁴)
17th to Last		(2 ³)
18th to Last		(2 ²)
19th to Last		(2 ¹)
20th to Last	LSB of N (2 ⁰)	

Note. The actual divide code is N+1, i.e., the number loaded plus 1.

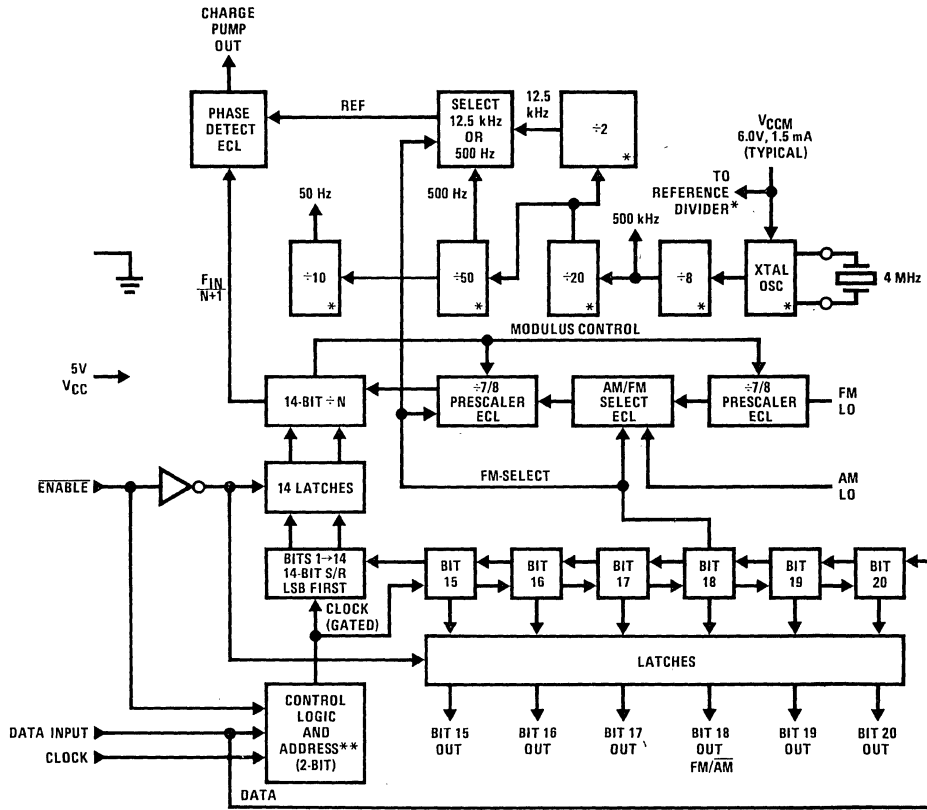
Typical Application Additional application notes are located at the back of section 11.

Electronically Tuned Radio Controller System; Direct Drive LED



Logic Diagram

AM/FM PLL Synthesizer



* Sections operating from V_CCM supply
 ** Address (1, 1)

DS8907 AM/FM Digital Phase-Locked Loop Frequency Synthesizer

General Description

The DS8907 is a PLL synthesizer designed specifically for use in AM/FM radios. It contains the reference oscillator, a phase comparator, a charge pump, a 120 MHz ECL/ 1^2L dual modulus programmable divider, and an 18-bit shift register/latch for serial data entry. The device is designed to operate with a serial data controller generating the necessary division codes for each frequency, and logic state information for radio function inputs/outputs.

The Colpitts reference oscillator for the PLL operates at 4 MHz. A chain of dividers is used to generate a 500 kHz clock signal for the external controller. Additional dividers generate a 25 kHz reference signal for FM and a 10 kHz reference signal for AM. One of these reference signals is selected by the data from the controller for use by the phase comparator.

Data is transferred between the frequency synthesizer and the controller via a 3 wire bus system. This consists of a data input line, an enable line, and a clock line. When the enable line is low, data can be shifted from the controller into the frequency synthesizer. When the enable line is transitioned from low to high, data entry is disabled and data present in the shift register is latched.

From the controller 20-bit data stream, the first 2 bits address the device permitting other devices to share the same bus. Of the remaining 18-bit data word, the next 13 bits are used for the PLL divide code. The remaining 5 bits are connected via latches to output pins. These 5 bits can be used to drive radio functions such as gain, mute, FM, AM and stereo only. These outputs are open collector. Bit 16 is used internally to select the AM or FM local oscillator input and to select between the 10 kHz and 25 kHz reference. A high level at bit 16 indicates FM and a low level indicates AM.

The PLL consists of a 13-bit programmable 1^2L divider, an ECL phase comparator, an ECL dual modulus ($p/p+1$) prescaler, and a high speed charge pump. The programmable divider divides by $(N+1)$, N being the number loaded into the shift register (bits 1–13 after address). It is clocked by the AM input via an ECL $\div 7/8$ prescaler, or through a $\div 63/64$ prescaler from the FM input. The AM input will work at frequencies up to 15 MHz, while the FM input works up to 120 MHz. The AM band is tuned with a frequency resolution of 10 kHz and the FM band is tuned with a resolution of 25 kHz. The buffered AM and FM inputs are self biased and can be driven directly by the VCO through a capacitor. The ECL phase comparator produces very accurate resolution of the phase difference between the input signal and the reference oscillator. The high speed charge pump consists of a switchable constant

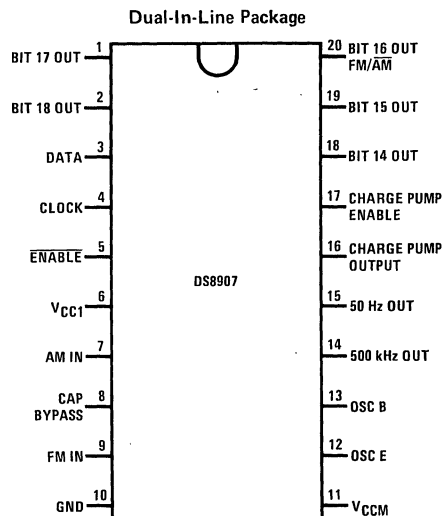
current source (-0.3 mA) and a switchable constant current sink ($+0.3$ mA). If the VCO frequency is low, the charge pump will source current, and sink current if the VCO frequency is high. When using an AFC the charge pump output may be forced into TRI-STATE[®] by applying a low level to the charge pump enable input.

A separate V_{CCM} pin (typically drawing 1.5 mA) powers the oscillator and reference chain to provide controller clocking frequencies when the balance of the PLL is powered down.

Features

- Uses inexpensive 4 MHz reference crystal
- F_{IN} capability greater than 120 MHz allows direct synthesis at FM frequencies
- FM resolution of 25 kHz allows usage of 10.7 MHz ceramic filter distribution
- Serial data entry for simplified control
- 50 Hz output for "time-of-day" reference driven from separate low power V_{CCM}
- 5-open collector buffered outputs for controlling various radio functions
- Separate AM and FM inputs. AM input has 15 mV (typical) hysteresis

Connection Diagram



Order Number DS8907N
See NS Package N20A

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Absolute Maximum Ratings (Note 1)

Supply Voltage (V _{CC1}) (V _{CCM})	7V
Input Voltage	7V
Output Voltage	7V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage, V _{CC}			
V _{CC1}	4.75	5.25	V
V _{CCM}	4.5	6.0	V
Temperature, T _A	0	70	°C

DC Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IH}	Logical "1" Input Voltage	2.1			V	
I _{IH}	Logical "1" Input Current	V _{IN} = 2.7V	0	10	μA	
V _{IL}	Logical "0" Input Voltage			0.7	V	
I _{IL}	Logical "0" Input Current	Data, Clock, and ENABLE Inputs, V _{IN} = 0V	-5	-25	μA	
I _{IL}	Logical "0" Input Current	Charge Pump Enable, V _{IN} = 0V	-250	-450	μA	
I _{OH}	Logical "1" Output Current					
	All Bit Outputs, 50 Hz Output	V _{OH} = 5.25V		50	μA	
	500 kHz Output	V _{OH} = 2.4V, V _{CCM} = 4.5V		-250	μA	
V _{OL}	Logical "0" Output Voltage					
	All Bit Outputs	I _{OL} = 5 mA		0.5	V	
	50 Hz Output, 500 kHz Output	I _{OL} = 250 μA		0.5	V	
I _{CC1}	Supply Current (V _{CC1})	All Bit Outputs High	90	160	mA	
I _{CCM(STANDBY)}	V _{CCM} Supply Current	V _{CCM} = 6.0V, All Other Pins Open	1.5	4.0	mA	
I _{OUT}	Charge Pump Output Current	1.2V ≤ V _{OUT} ≤ V _{CCM} - 1.2V V _{CCM} ≤ 6.0V	Pump Up Pump Down TRI-STATE®	-0.10 0.10 0	-0.30 0.30 ±100	mA mA nA
I _{CCM(OPERATE)}	V _{CCM} Supply Current	V _{CCM} = 6.0V, V _{CC1} = 5.25V, All Other Pins Open	2.5	6.0	mA	

AC Electrical Characteristics V_{CC} = 5V, T_A = 25°C, t_r ≤ 10 ns, t_f ≤ 10 ns

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS	
V _{IN(MIN)} (F)	F _{IN} Minimum Signal Input	AM and FM Inputs, 0°C ≤ T _A ≤ 70°C	20	100	mV (rms)	
V _{IN(MAX)} (F)	F _{IN} Maximum Signal Input	AM and FM Inputs, 0°C ≤ T _A ≤ 70°C	1000	1500	mV (rms)	
F _{OPERATE}	Operating Frequency Range (Sine Wave Input)	V _{IN} = 100 mV rms 0°C ≤ T _A ≤ 70°C	AM FM	8 120	MHz MHz	
R _{IN} (FM)	AC Input Resistance, FM	120 MHz, V _{IN} = 100 mV rms	300		Ω	
R _{IN} (AM)	AC Input Resistance, AM	2 MHz, V _{IN} = 100 mV rms	1000		Ω	
C _{IN}	Input Capacitance, FM and AM	V _{IN} = 120 MHz	3	6	10	pF
t _{EN1}	Minimum ENABLE High Pulse Width		625	1250	ns	
t _{EN0}	Minimum ENABLE Low Pulse Width		375	750	ns	
t _{CLKEN0}	Minimum Time Before ENABLE Goes Low that CLOCK Must be Low		-50	0	ns	
t _{EN0CLK}	Minimum Time After ENABLE Goes Low that CLOCK Must Remain Low		275	550	ns	
t _{CLKEN1}	Minimum Time Before ENABLE Goes High that Last Positive CLOCK Edge May Occur		300	600	ns	

AC Electrical Characteristics (Continued) $V_{CC} = 5V, T_A = 25^\circ C, t_r \leq 10 ns, t_f \leq 10 ns$

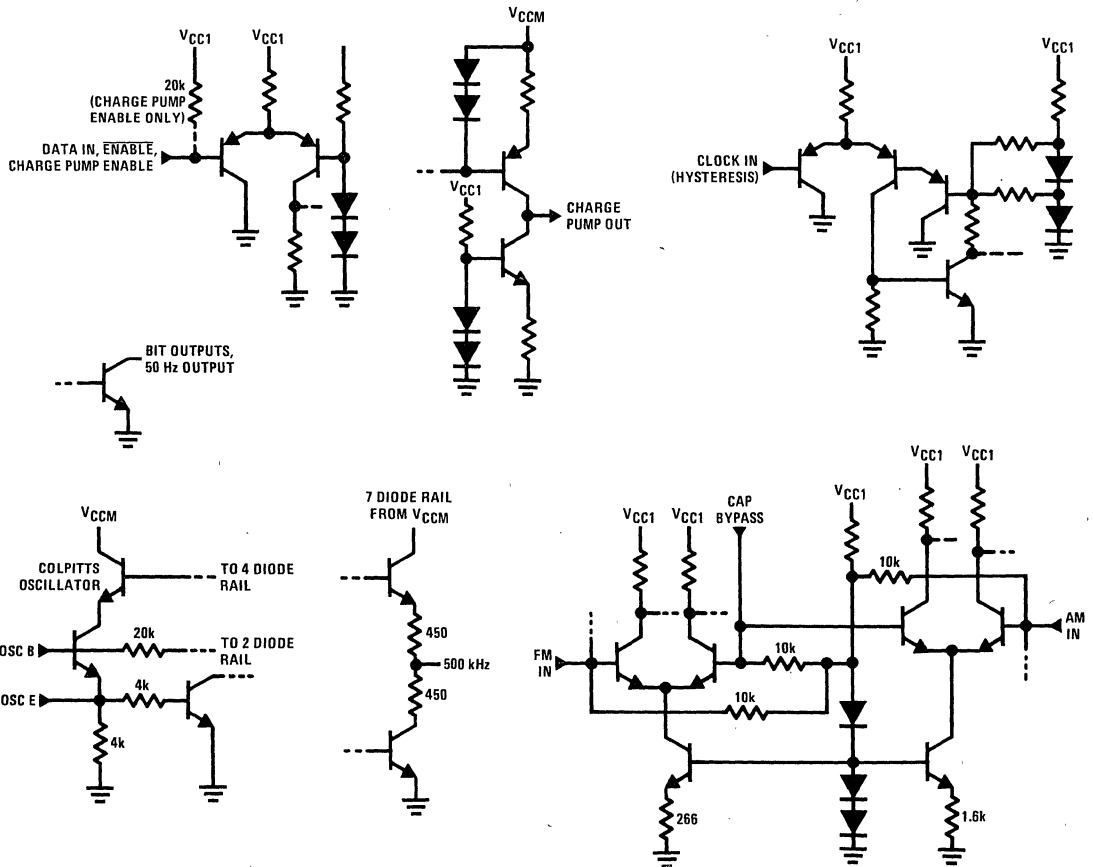
PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
tEN1CLK	Minimum Time After ENABLE Goes High Before an Unused Positive CLOCK Edge May Occur		175	350	ns
tCLKH	Minimum CLOCK High Pulse Width		275	550	ns
tCLKL	Minimum CLOCK Low Pulse Width		400	800	ns
tDS	Minimum DATA Setup Time, Minimum Time Before CLOCK that DATA Must be Valid		150	300	ns
tDH	Minimum DATA Hold Time, Minimum Time After CLOCK that DATA Must Remain Valid		400	800	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

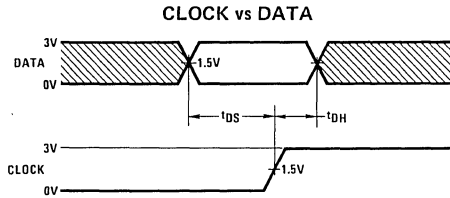
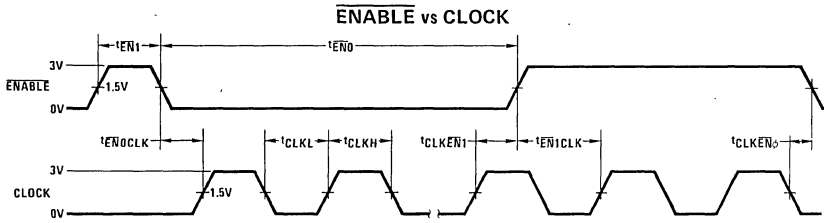
Note 2: Unless otherwise specified min/max limits apply across the $-40^\circ C$ to $+85^\circ C$ temperature range for the DS8907.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

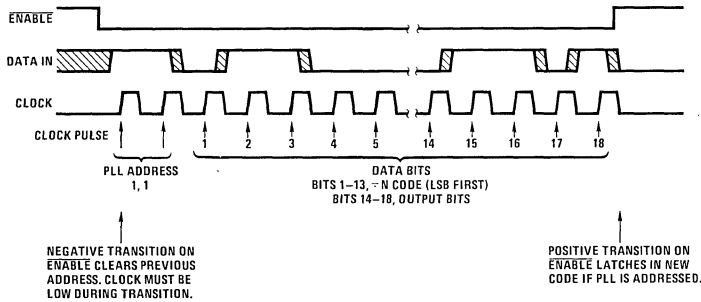
Schematic Diagrams (DS8907 AM/FM PLL Typical Input/Output Schematics)



Timing Diagrams*



AM/FM Frequency Synthesizer (Scan Mode)



*Timing diagrams are not drawn to scale. Scale within any one drawing may not be consistent, and intervals are defined positive as drawn.

SERIAL DATA ENTRY INTO THE DS8907

Serial information entry into the DS8907 is enabled by a low level on the ENABLE input. One binary bit is then accepted from the DATA input with each positive transition of the CLOCK input. The CLOCK input must be low for the specified time preceding and following the negative transition of the ENABLE input.

The first two bits accepted following the negative transition of the ENABLE input are interpreted as address. If these address bits are not 1,1, no further information will be accepted from the DATA inputs, and the internal data latches will not be changed when ENABLE returns high.

If these first two bits are 1,1, then all succeeding bits are accepted as data, and are shifted successively into the internal shift register as long as ENABLE remains low.

Any data bits preceding the 18th to last bit will be shifted out, and thus are irrelevant. Data bits are counted as any bits following two valid address bits (1,1) with the ENABLE low. When the ENABLE input returns high, any further serial data entry is inhibited. Upon this positive transition, the data in

the internal shift register is transferred into the internal data latches. Note that until this time, the states of the internal data latches have remained unchanged.

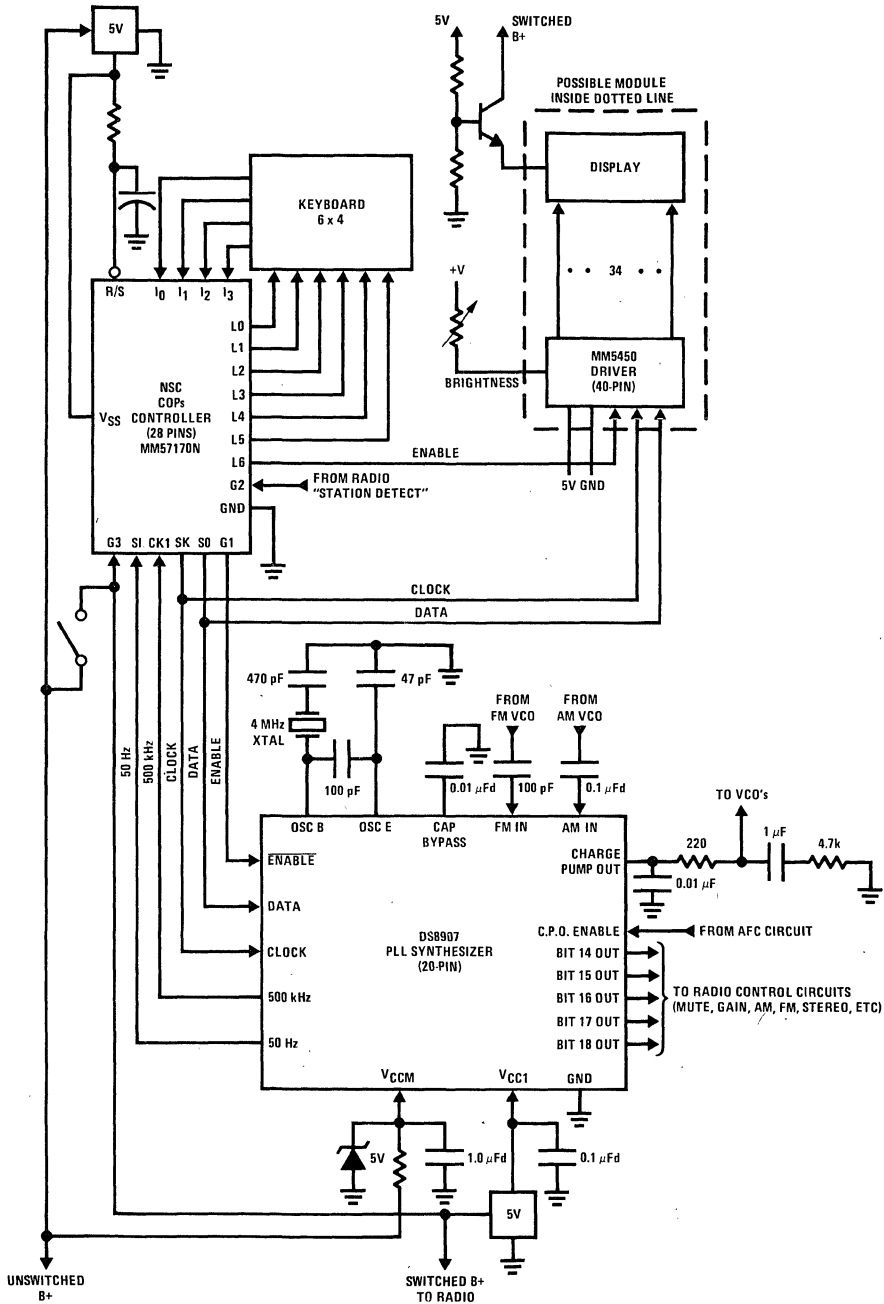
These data bits are interpreted as follows:

DATA BIT POSITION	DATA INTERPRETATION
Last	Bit 18 Output (Pin 2)
2nd to Last	Bit 17 Output (Pin 1)
3rd to Last	Bit 16 Output (FM/AM) (Pin 20)
4th to Last	Bit 15 Output (Pin 19)
5th to Last	Bit 14 Output (Pin 18)
6th to Last	MSB of ÷N (2 ¹²)
7th to Last	(2 ¹¹)
8th to Last	(2 ¹⁰)
9th to Last	(2 ⁹)
10th to Last	(2 ⁸)
11th to Last	(2 ⁷)
12th to Last	(2 ⁶)
13th to Last	(2 ⁵)
14th to Last	(2 ⁴)
15th to Last	(2 ³)
16th to Last	(2 ²)
17th to Last	(2 ¹)
18th to Last	LSB of ÷N (2 ⁰)

Note. The actual divide code is N+1, i.e., the number loaded plus 1.

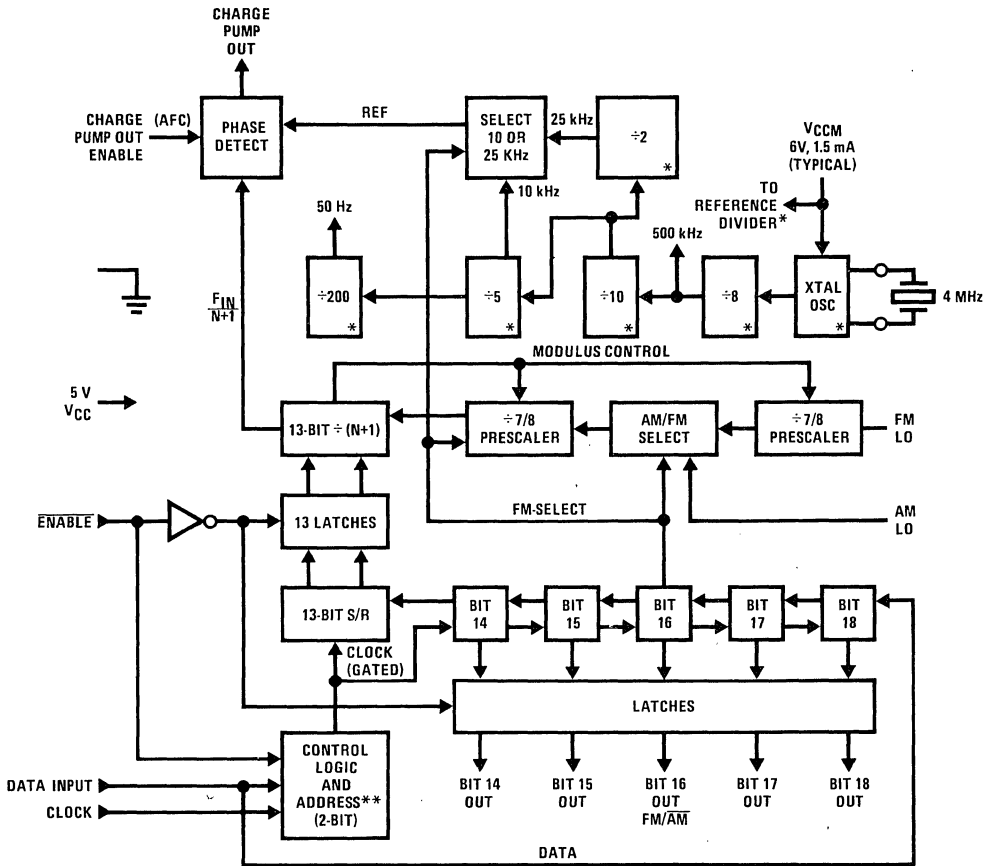
Typical Application Additional application notes are located at the back of section 11.

Electronically Tuned Radio Controller System; Direct Drive LED



Logic Diagram

AM/FM PLL/Synthesizer (Serial Data 20-Pin Package)



* Sections operating from VCCM supply.

** Address (1, 1)

DS8908 AM/FM Digital Phase-Locked Loop Frequency Synthesizer

General Description

The DS8908 is a PLL synthesizer designed specifically for use in AM/FM radios. It contains the reference oscillator, a phase comparator, a charge pump, an operational amplifier, a 120 MHz ECL/1²L dual modulus programmable divider, and a 19-bit shift register/latch for serial data entry. The device is designed to operate with a serial data controller generating the necessary division codes for each frequency, and logic state information for radio function inputs/outputs.

A 3.96 MHz pierce oscillator and divider chain generate a 1.98 MHz external controller clock, a 20 kHz, 10 kHz, 9 kHz, and 1 kHz reference signals, and a 50 Hz time-of-day signal. The oscillator and divider chain are sourced by the V_{CCM} pin thus providing a low power controller clock drive and time-of-day indication when the balance of the PLL is powered down.

The 21-bit serial data stream is transferred between the frequency synthesizer and the controller via a 3-wire bus system comprised of a data line, a clock line, and an enable line.

The first 2 bits in the serial data stream address the synthesizer thus permitting other devices such as display drivers to share the same bus. The next 14 bits are used for the PLL (N + 1) divide code. The 15th bit is used internally to select the AM or FM local oscillator input. A high level on this bit enables the FM input and a low level enables the AM input. The 16th and 17th bits are used to select one of the 4 reference frequencies. The 18th and 19th bits are connected via latches to open collector outputs. These outputs can be used to drive radio functions such as gain, mute, AM, FM, or charge pump current source levels.

The PLL consists of a 14-bit programmable 1²L divider, an ECL phase comparator, an ECL dual modulus (p/p + 1) prescaler, a high speed charge pump, and an operational amplifier. The programmable divider divides by (N + 1), N being the number loaded into the shift register. The programmable divider is clocked through a ÷7/8 prescaler by the AM input or through a ÷63/64 prescaler by the FM input. The AM input will work at frequencies up to 15 MHz, while the FM input works up to 120 MHz. The VCO can be tuned with a frequency resolution of either 1 kHz, 9 kHz, 10 kHz, or 20 kHz. The buffered AM and FM inputs are self-biased and can be driven directly by the VCO through a capacitor. The ECL phase comparator produces very accurate resolution of the phase difference between the input signal and the reference oscillator. The high speed charge pump consists of a switchable constant current source and sink. The charge pump can be programmed to deliver from 75 μA to 750 μA of constant current by connection of an external resistor from pin R_{PROGRAM} to ground or the open collector bit outputs. Connection of programming resistors to the bit outputs enables the controller to adjust the

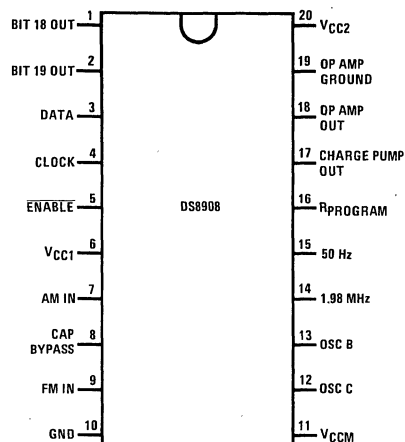
loop gain for the particular reference frequency selected. The charge pump will source current if the VCO frequency is high and sink current if the VCO frequency is low. The low noise operational amplifier provided has a high impedance JFET input and a large output voltage range. The op amp's negative input is common with the charge pump output and its positive input is internally biased.

Features

- Uses inexpensive 3.96 MHz reference crystal
- F_{IN} capability greater than 120 MHz allows direct synthesis at FM frequencies
- FM resolution of either 10 kHz or 20 kHz allows usage of 10.7 MHz ceramic filter distribution
- Serial data entry for simplified control
- 50 Hz output for time-of-day reference driven from separate low power V_{CCM}
- 2 open collector buffered outputs for controlling various radio functions or loop gain
- Separate AM and FM inputs; AM input has 15 mV (typical) hysteresis
- Programmable charge pump current sources enable adjustment of system loop gain
- Operational amplifier provides high impedance load to charge pump output and a wide voltage range for the VCO input

Connection Diagram

Dual-In-Line Package



TOP VIEW

Order Number DS8908N
See NS Package N20A

Absolute Maximum Ratings (Note 1)**Operating Conditions**

		Min	Max	Units
Supply Voltage (V_{CC1})(V_{CCM}) (V_{CC2})	7V 17V	4.5 $V_{CC1} + 1.5$	5.5 15.0	V
Input Voltage	7V	3.5	5.5	V
Output Voltage	7V	-40	+85	°C
Storage Temperature Range	-65°C to +150°C			
Lead Temperature (Soldering, 10 seconds)	300°C			

DC Electrical Characteristics (Notes 2 and 3)

Parameter	Conditions	Min	Typ	Max	Units	
V_{IH} Logical "1" Input Voltage		2.0			V	
I_{IH} Logical "1" Input Current	$V_{IN} = 2.7V$		0	10	μA	
V_{IL} Logical "0" Input Voltage				0.8	V	
I_{IL} Logical "0" Input Current	Data, Clock, and ENABLE Inputs, $V_{IN} = 0V$		-5	-25	μA	
I_{OH} Logical "1" Output Current All Bit Outputs, 50 Hz Output 1.98 MHz Output	$V_{OH} = 5.5V$			50	μA	
	$V_{OH} = 2.4V$, $V_{CCM} = 4.5V$			-250	μA	
V_{OL} Logical "0" Output Voltage All Bit Outputs 50 Hz Output, 1.98 MHz Output 1.98 MHz Output	$I_{OL} = 5 mA$			0.5	V	
	$I_{OL} = 250 \mu A$			0.5	V	
	$I_{OL} = 20 \mu A$, $T_A > 70^\circ C$ $I_{OL} = 20 \mu A$, $T_A \leq 70^\circ C$			0.3 0.4	V	
I_{CC1} Supply Current (V_{CC1})	All Bit Outputs High			160	mA	
I_{CCM} V_{CCM} Supply Current	$V_{CCM} = 5.5V$, All Other Pins Open		2.5	4.0	mA	
I_{OUT} Charge Pump Output Current	3.33k $\leq R_{PROG} \leq 33.3k$ I_{OUT} Measured Between Pin 17 and Pin 18 $I_{PROG} = V_{CC1}/2 R_{PROG}$	Pump Up	-20	I_{PROG}	+20	%
		Pump Down	-20	I_{PROG}	+20	%
		TRI-STATE®		0	± 250	nA
I_{CC2} V_{CC2} Supply Current	$V_{CCM} = 5V$, $V_{CC1} = 5.5V$, $V_{CC2} = 15V$ All Other Pins Open		6.7	11	mA	
OP_{VOH} Op Amp Minimum High Level	$V_{CC1} = 4.5V$, $I_{OH} = -750 \mu A$	$V_{CC2} - 0.4$			V	
OP_{VOL} Op Amp Maximum Low Level	$V_{CC1} = 5.5V$, $I_{OL} = 750 \mu A$			0.6	V	
CPO_{BIAS} Charge Pump Bias Voltage Delta	CPO Shorted to Op Amp Output CPO = TRI-STATE Op Amp I_{OL} : 750 μA vs -750 μA			100	mV	

AC Electrical Characteristics $V_{CC} = 5V$, $T_A = 25^\circ C$, $t_r \leq 10 ns$, $t_f \leq 10 ns$

Parameter	Conditions	Min	Typ	Max	Units
$V_{IN(MIN)(F)}$ F_{IN} Minimum Signal Input	AM and FM Inputs, $-40^\circ C \leq T_A \leq 85^\circ C$		20	100	mV(rms)
$V_{IN(MAX)(F)}$ F_{IN} Maximum Signal Input	AM and FM Inputs, $-40^\circ C \leq T_A \leq 85^\circ C$	1000	1500		mV(rms)
$F_{OPERATE}$ Operating Frequency Range (Sine Wave Input)	$V_{IN} = 100 mV rms$ $-40^\circ C \leq T_A \leq 85^\circ C$				
	AM	0.5		15	MHz
	FM	80		120	MHz
$R_{IN}(FM)$ AC Input Resistance, FM	120 MHz, $V_{IN} = 100 mV rms$	600			Ω
$R_{IN}(AM)$ AC Input Resistance, AM	15 MHz, $V_{IN} = 100 mV rms$	1000			Ω
C_{IN} Input Capacitance, FM and AM	$V_{IN} = 120 MHz (FM)$, 15 MHz (AM)	3	6	10	pF
t_{EN1} Minimum ENABLE High Pulse Width			625	1250	ns

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AC Electrical Characteristics (Continued) $V_{CC} = 5V, T_A = 25^\circ C, t_r \leq 10 ns, t_f \leq 10 ns$

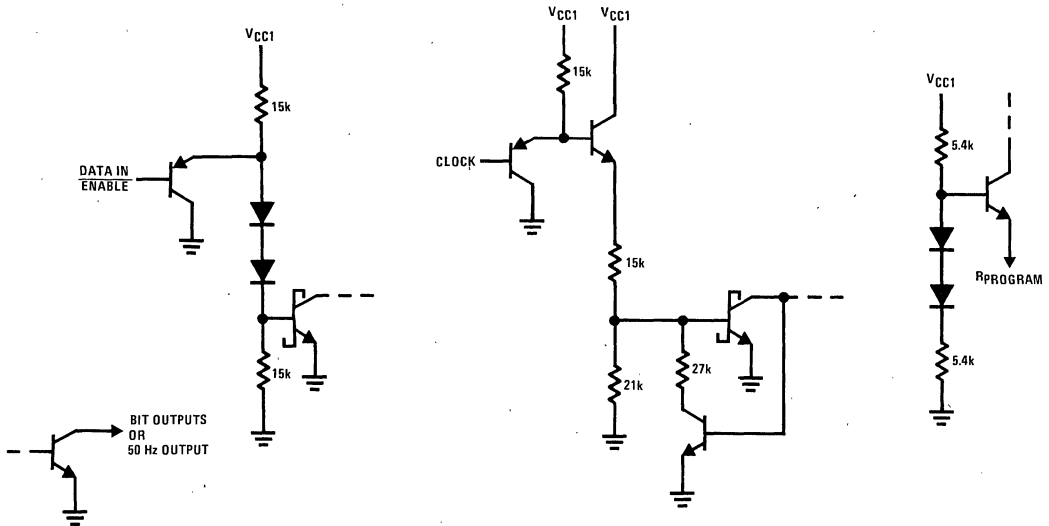
Parameter	Conditions	Min	Typ	Max	Units
t_{EN0}	Minimum \overline{ENABLE} Low Pulse Width		375	750	ns
$t_{CLK\overline{EN}0}$	Minimum Time Before \overline{ENABLE} Goes Low that $CLOCK$ Must be Low		-50	0	ns
$t_{\overline{EN}0CLK}$	Minimum Time After \overline{ENABLE} Goes Low that $CLOCK$ Must Remain Low		275	550	ns
$t_{CLK\overline{EN}1}$	Minimum Time Before \overline{ENABLE} Goes High that Last Positive $CLOCK$ Edge May Occur		300	600	ns
$t_{\overline{EN}1CLK}$	Minimum Time After \overline{ENABLE} Goes High Before an Unused Positive $CLOCK$ Edge May Occur		175	350	ns
t_{CLKH}	Minimum $CLOCK$ High Pulse Width		275	550	ns
t_{CLKL}	Minimum $CLOCK$ Low Pulse Width		400	800	ns
t_{DS}	Minimum $DATA$ Set-Up Time, Minimum Time Before $CLOCK$ that $DATA$ Must be Valid		150	300	ns
t_{DH}	Minimum $DATA$ Hold Time, Minimum Time After $CLOCK$ that $DATA$ Must Remain Valid		400	800	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

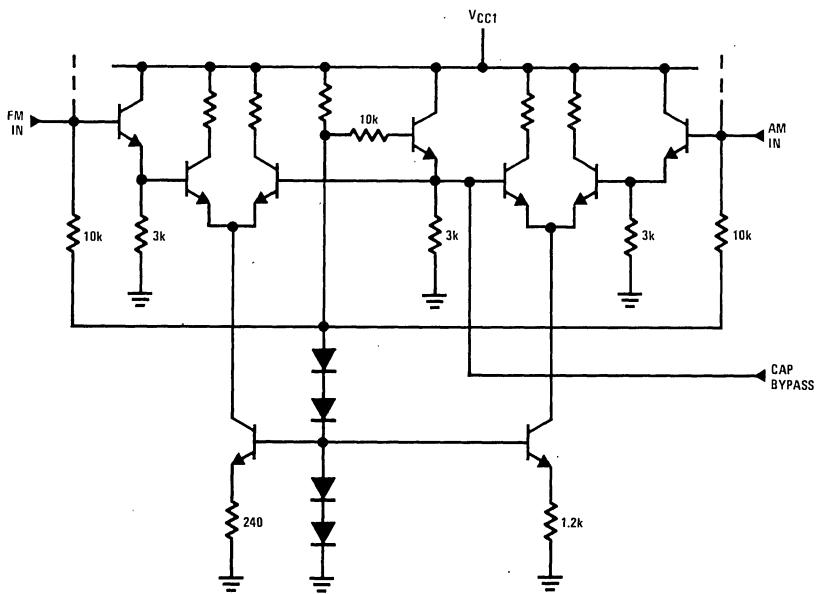
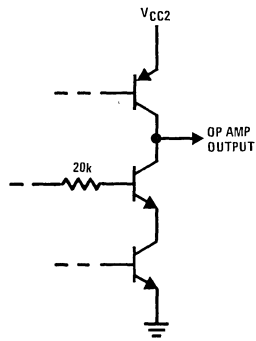
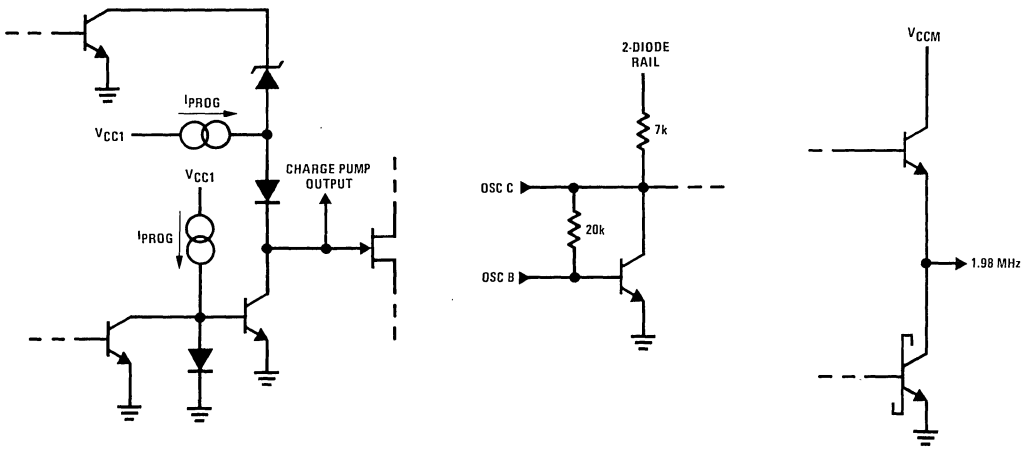
Note 2: Unless otherwise specified min/max limits apply across the $-40^\circ C$ to $+85^\circ C$ temperature range for the DS8908.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

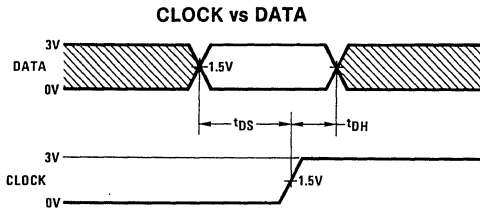
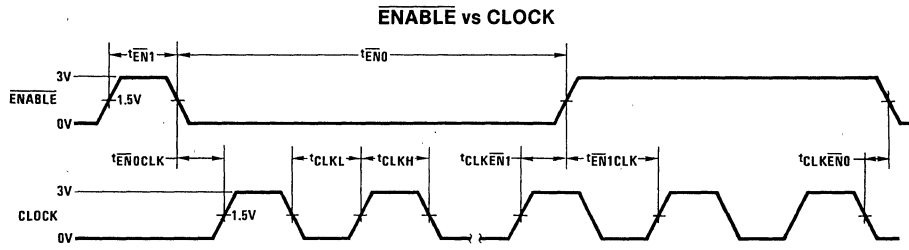
Schematic Diagrams (DS8908 AM/FM PLL Typical Input/Output Schematics)



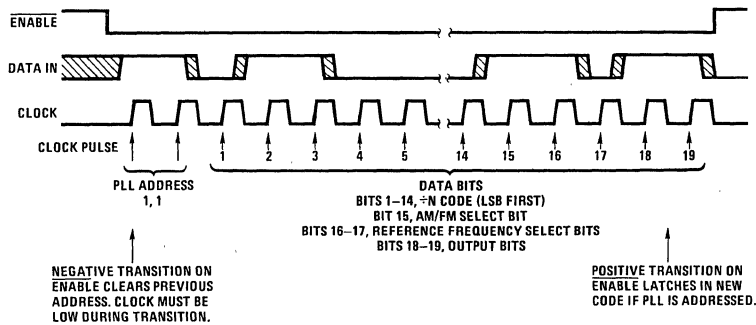
Schematic Diagrams (Continued)



Timing Diagrams*



AM/FM Frequency Synthesizer (Scan Mode)



*Timing diagrams are not drawn to scale. Scale within any one drawing may not be consistent, and intervals are defined positive as drawn.

Serial Data Entry into the DS8908

Serial information entry into the DS8908 is enabled by a low level on the ENABLE input. One binary bit is then accepted from the DATA input with each positive transition of the CLOCK input. The CLOCK input must be low for the specified time preceding and following the negative transition of the ENABLE input.

The first two bits accepted following the negative transition of the ENABLE input are interpreted as address. If these address bits are *not* 1,1, no further information will be accepted from the DATA inputs, and the internal data latches will *not* be changed when ENABLE returns high.

If these first two bits are 1,1, then all succeeding bits are *accepted* as data, and are shifted successively into the internal shift register as long as ENABLE remains low.

Any data bits preceding the 19th to last bit will be shifted out, and thus are irrelevant. Data bits are counted as any bits *following* two valid address bits (1,1) with the ENABLE low. When the ENABLE input returns high, any further serial data entry is inhibited. Upon this positive transition, the data in the internal shift register is transferred into the internal data latches. Note that until this time, the states of the internal data latches have remained unchanged.

These data bits are interpreted as follows:

Data Bit Position	Data Interpretation
Last	Bit 19 Output (Pin 2)
2nd to Last	Bit 18 Output (Pin 1)
3rd to Last	Ref. Freq. Select Bit ⁽¹⁾ 17
4th to Last	Ref. Freq. Select Bit ⁽¹⁾ 16
5th to Last	AM/FM Select Bit 15
6th to Last	(2 ¹³)
7th to Last	(2 ¹²)
8th to Last	(2 ¹¹)
9th to Last	(2 ¹⁰)
10th to Last	(2 ⁹)
11th to Last	(2 ⁸)
12th to Last	(2 ⁷)
13th to Last	(2 ⁶)
14th to Last	(2 ⁵)
15th to Last	(2 ⁴)
16th to Last	(2 ³)
17th to Last	(2 ²)
18th to Last	(2 ¹)
19th to Last	LSB of ÷N (2 ⁰)

} ÷ N⁽²⁾

Note 1: See Reference Frequency Select Truth Table.

Note 2: The actual divide code is N + 1, i.e., the number loaded plus 1.

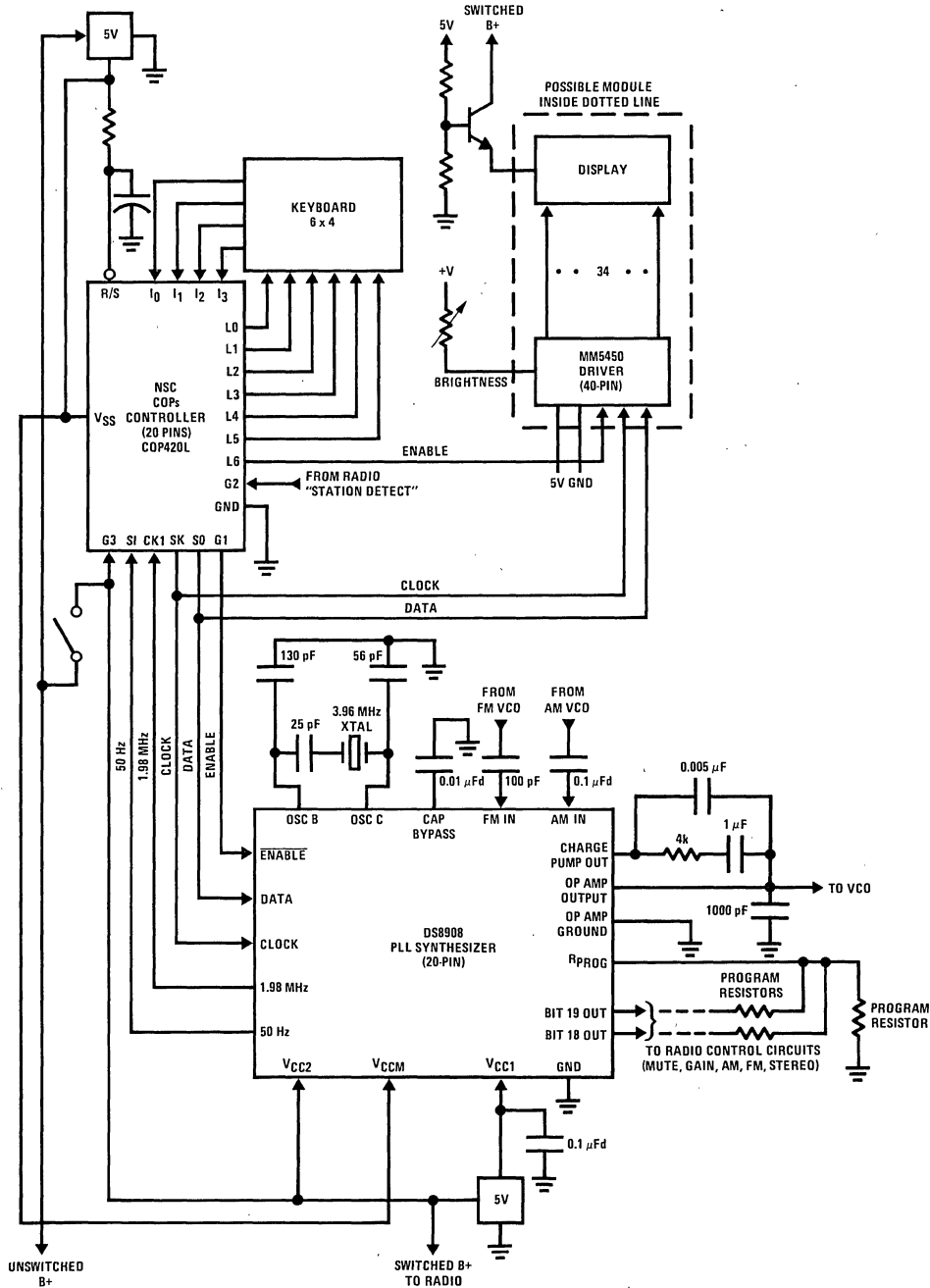
Truth Table

REFERENCE FREQUENCY SELECTION TRUTH TABLE

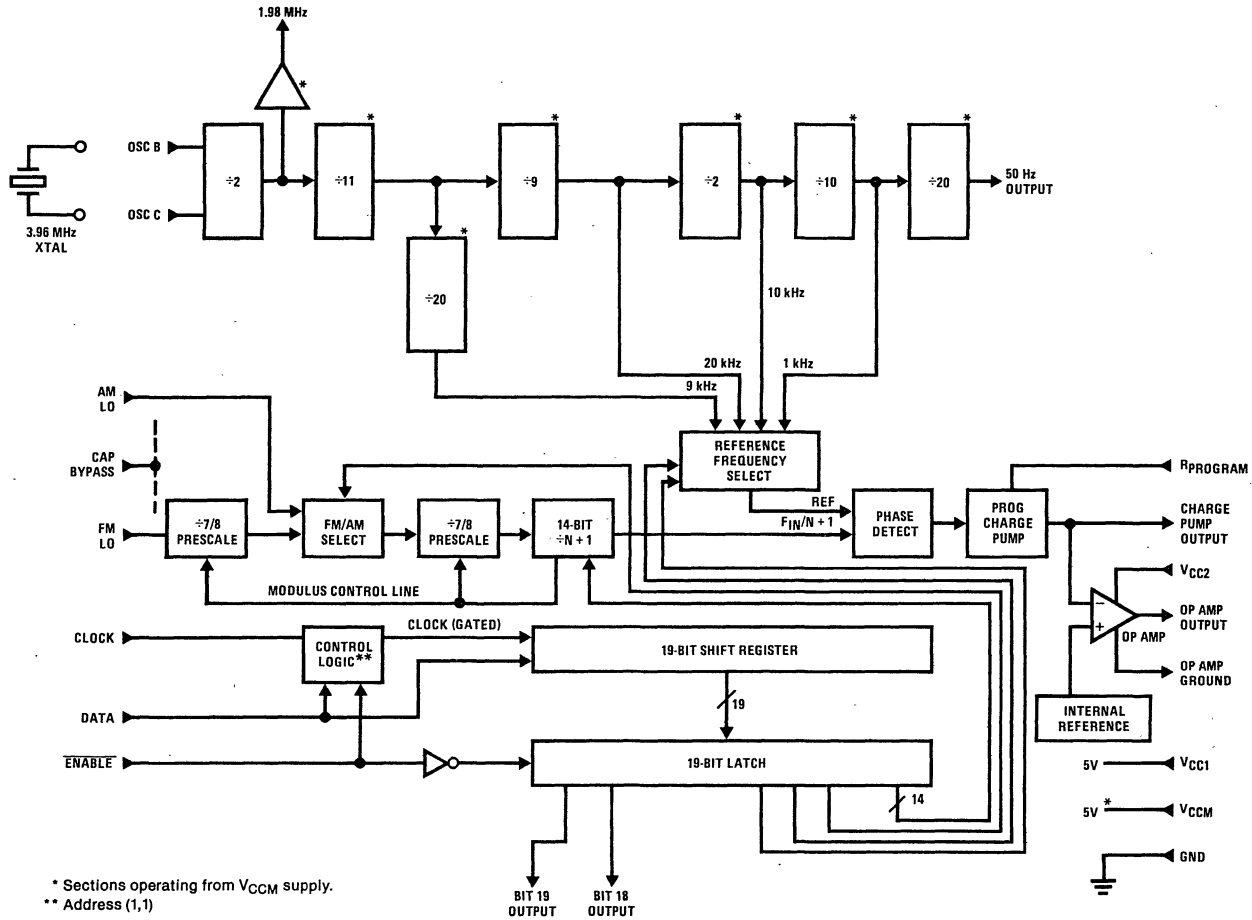
Serial Data		Reference Frequency
Bit 16	Bit 17	(kHz)
1	1	20
1	0	10
0	1	9
0	0	1

Typical Application Additional application notes are located at the back of section 11.

Electronically Tuned Radio Controller System; Direct Drive LED



AM/FM PLL/Synthesizer (Serial Data 20-Pin Package)



* Sections operating from V_{CCM} supply.
 ** Address (1,1)

DS8614, DS8615, DS8616, DS8617 130/225 MHz Low Power Dual Modulus Prescalers

General Description

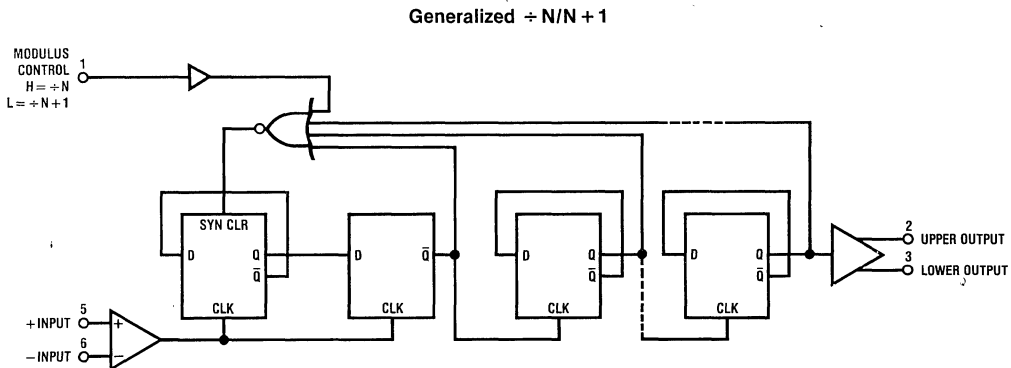
The DS8614 series products are low power dual modulus prescalers which divide by 20/21, 32/33, 40/41, and 64/65, respectively. The modulus control (MC) input selects division by N when at a high TTL level and division by N + 1 when at a low TTL level. The clock inputs are buffered, providing 40 mVrms input sensitivity. The two outputs provide the user the option to wire either a totem-pole or open-collector output structure. Additionally, the user can wire a resistor between the two output pins to minimize edge transition emissions. The outputs are designed to drive positive edge triggered PLLs. These products can be operated from either an unregulated 6.8V to 13.5V source or regulated 5V \pm 10% source. Unregulated operation is obtained by connecting V_S to the source with V_{REG} open. Regulated operation is obtained by connecting both V_S and V_{REG} to the supply source.

The device can be used in phase-locked loop applications such as FM radio or other communications bands to pre-scale the input frequency down to a more usable level. A digital frequency display system can also be derived separately or in conjunction with a phase-locked loop, and it can extend the useful range of many inexpensive frequency counters to 225 MHz.

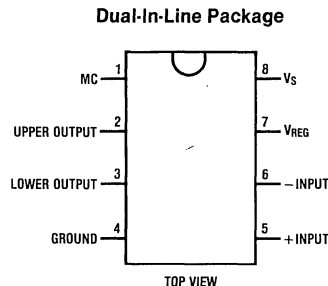
Features

- Input frequency: 130 MHz (-4, -3); 225 MHz (-2, std)
- Low power: 10 mA (-4, -2); 7 mA (-3, std)
- Input sensitivity: 100 mVrms (-4, -3); 40 mVrms (-2, std)
- Pin compatible with Motorola MC12015-17 prescalers
- Unregulated/regulated power supply option

Logic Diagram



Connection Diagram



**Order Number DS8614N, DS8615N,
DS8616N or DS8617N (-4, -3, -2)
See NS Package N08E**

Absolute Maximum Ratings (Note 1)

V_S , Unregulated Supply Voltage	15V
V_{REG} , Regulated Supply Voltage	7V
Modulus Control Input Voltage	7V
Open-Collector Output Voltage	7V
Operating Free Air Temperature Range	-30°C to +70°C
Storage Temperature Range	-65°C to +150°C

Recommended Operating Conditions

Symbol	Parameter	Conditions	DS8614-4 DS8615-4 DS8616-4 DS8617-4		DS8614-3 DS8615-3 DS8616-3 DS8617-3		DS8614-2 DS8615-2 DS8616-2 DS8617-2		DS8614 DS8615 DS8616 DS8617		Units
			Min	Max	Min	Max	Min	Max	Min	Max	
V_S	Unregulated Supply Voltage	$V_{REG} = \text{Open}$	6.8	13.5	6.8	13.5	6.8	13.5	5.5	13.5	V
V_{REG}	Regulated Supply Voltage	V_S and V_{REG} Shorted	4.5	5.5	4.5	5.5	4.5	5.5	4.5	5.5	V
f_{MAX}	Toggle Frequency	$V_{IN} = 100$ mVrms	20	130	20	130		225		225	MHz
V_{IN}	Input Signal Amplitude		100	300	100	300	40	300	40	300	mVrms
V_{SLW}	Slew Rate		20		20		20		20		V/ μ s
I_{OH}	High Level Output Current			-400		-400		-400		-400	μ A
I_{OL}	Low Level Output Current			2.0		2.0		2.0		2.0	mA

DC Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	DS8614-4 DS8615-4 DS8616-4 DS8617-4		DS8614-3 DS8615-3 DS8616-3 DS8617-3		DS8614-2 DS8615-2 DS8616-2 DS8617-2		DS8614 DS8615 DS8616 DS8617		Units
			Min	Max	Min	Max	Min	Max	Min	Max	
V_{IH}	High Level MC Input Voltage	$V_S = 13.5V$, $V_{REG} = \text{Open}$	2.0		2.0		2.0		2.0		V
V_{IL}	Low Level MC Input Voltage	$V_{REG} = V_S = 4.5V$		0.8		0.8		0.8		0.8	V
V_{OH}	High Level Output Voltage	$I_{OH} = -0.4$ mA, Pins 2 and 3 Shorted	$V_{REG} - 2$		$V_{REG} - 2$		$V_{REG} - 2$		$V_{REG} - 2$		V
I_{CEX}	Open-Collector High Level Output	Lower Output = 5.5V		100		100		100		100	μ A
V_{OL}	Low Level Output Voltage	$V_{REG} = 4.5V$, $I_{OL} = 2$ mA		0.5		0.5		0.5		0.5	V
I_I	Max MC Input Current	$V_S = 13.5V$, $V_{REG} = \text{Open}$, $V_{IH} = 7V$		100		100		100		100	μ A
I_{IH}	High Level MC Input Current	$V_{REG} = 4.5V$, $V_{IH} = 2.7V$		20		20		20		20	μ A
I_{IL}	Low Level MC Input Current	$V_S = 13.5V$, $V_{REG} = \text{Open}$, $V_{IL} = 0.4V$		-200		-100		-200		-100	μ A
I_S	Supply Current, Unregulated Mode	$V_S = 13.5V$, $V_{REG} = \text{Open}$		10		7		10		7	mA
I_{REG}	Supply Current, Regulated Mode	$V_S = V_{REG} = 5.5V$		10		7		10		7	mA

AC Electrical Characteristics $V_{CC} = 5V \pm 10\%$, $T_A = -30^\circ C$ to $70^\circ C$

Symbol	Parameter	Conditions	Min	Max	Units
$t_{MODULUS}$	Modulus Set-Up Time (Notes 4 and 5)	DS8614		55	
		DS8615, DS8616		65	ns
		DS8617		75	
R_{IN}	AC Input Resistance	$V_{IN} = 100$ MHz and 50 mVrms	1.0		k Ω
C_{IN}	Input Capacitance	$V_{IN} = 100$ MHz and 50 mVrms	3	10	pF

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

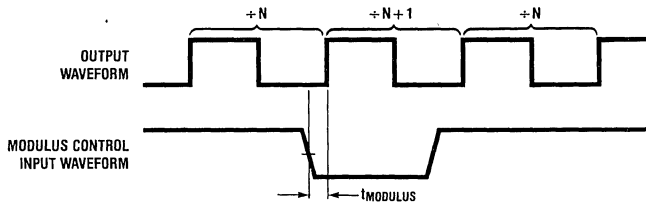
Note 2: Unless otherwise specified min/max limits apply across the $-30^\circ C$ to $+70^\circ C$ temperature range.

Note 3: All currents into device pins are shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: $t_{MODULUS}$ is the period of time the modulus control level must be defined prior to the positive transition of the prescaler output to ensure proper modulus selection.

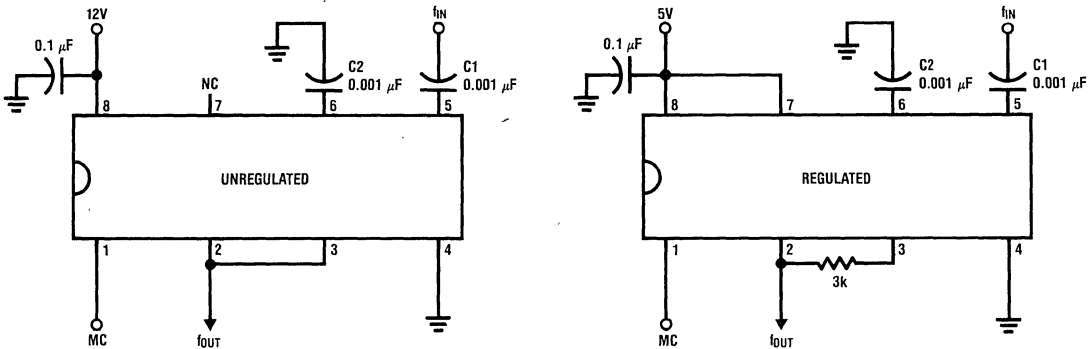
Note 5: See Timing Diagrams.

Timing Diagram

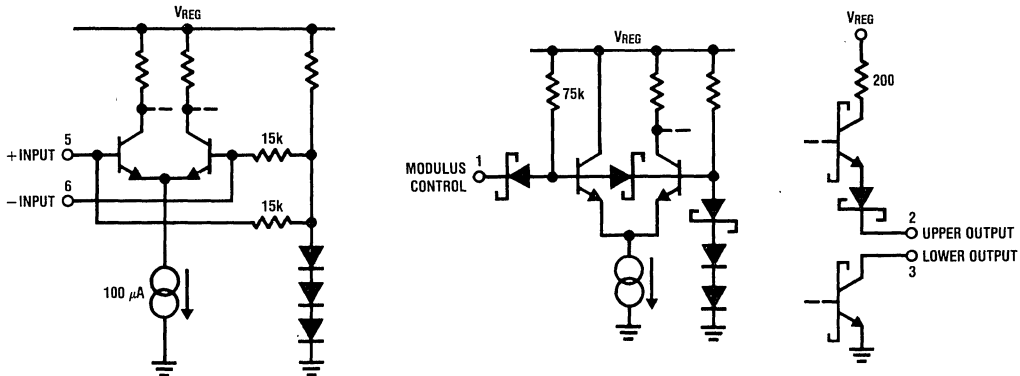


The logic state of the modulus control input just prior to the output's rising edge will determine the modulus ratio of the device immediately following that rising edge. The pulse width difference of N and $N + 1$ operation occurs during the output = HI condition.

Typical Applications



Schematic Diagrams



Application Hints

OPERATING NOTES

The signal source is usually capacitively coupled to the input. At higher frequencies a 0.001 μF input capacitor (C1) is usually sufficient, with larger values used at the lower frequencies. If the input signal is likely to be interrupted, it may be desirable to connect a 100 k Ω resistor between one input and ground to stabilize the device. In the single-ended mode, it is preferable to connect the resistor to the unused input. In the differential mode, the resistor can be connected to either input. The addition of the 100 k Ω pull-down resistor causes a loss of input sensitivity, but prevents circuit oscillations under no signal (open circuit) conditions. In addition, in the single ended mode, a capacitor of 0.001 μF (C2) should be connected between the

unused input and the ground plane to provide a good high frequency bypass. The capacitor should be made larger for lower frequencies.

The input waveform may be sinusoidal, but below about 20 MHz the operation of the circuit becomes dependent on the slew rate of the input rather than amplitude. A square wave input with a slew rate of greater than 20V/ μs will permit correct operation down to lower frequencies, provided the proper input coupling capacitor is provided.

For regulated mode operation connect V_S to V_{REG} to ensure proper operation (see Typical Application diagram).

DS8626 120 MHz Divide-by-40 Prescaler DS8629 120 MHz Divide-by-100 Prescaler

General Description

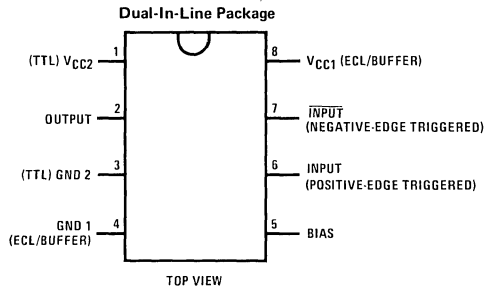
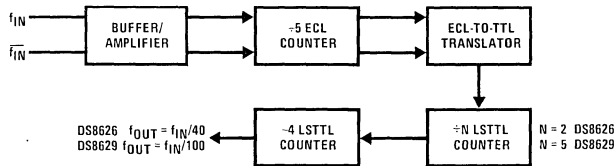
The DS8626 and DS8629 are fixed ratio counters combining ECL and Low Power Schottky technology on a single monolithic substrate. Both provide high frequency capability and TTL compatibility. A single 5.2V $\pm 10\%$ supply is needed.

The device can be operated in a single-ended or differential input mode, with the signal source typically capacitively coupled to the input. An input amplifier is included to allow use of extremely small amplitude, high frequency signals. The output of the device is a square wave of frequency $f_{OUT} = f_{IN}/100$ for the DS8629 and $f_{OUT} = f_{IN}/40$ for the DS8626. The output is standard Low Power Schottky.

Features

- High frequency, dc–120 MHz—small input amplitude
- Sine wave input $30\text{ MHz} < f_{IN} < 120\text{ MHz}$
- TTL compatible output
- May be used with TTL input
- Single supply operation 5.2V $\pm 10\%$
- Single ended or differential input modes
- Positive or negative-edge triggered
- Count down sequence avoids broadcast FM IF harmonics

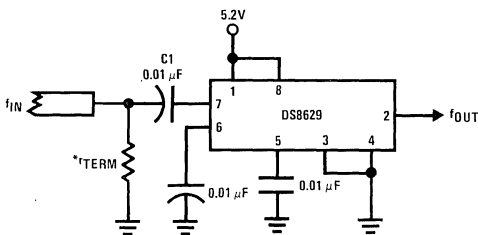
Logic and Connection Diagrams



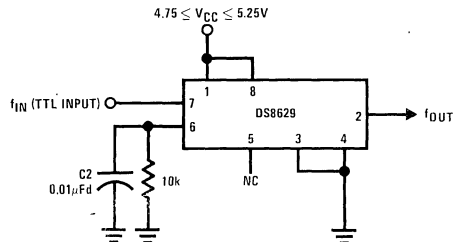
Order Number DS8626N or DS8629N
See NS Package N08A

Typical Applications

High Frequency—Single-Ended Input



TTL Input—dc $< f_{IN} < f_{MAX}$



* f_{TERM} is the termination impedance

Absolute Maximum Ratings (Note 1)

Supply Voltage	7V
Input Voltage	5V
Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})	4.68	5.72	V
Temperature (T_A)	0	+70	°C

Electrical Characteristics (Notes 2 and 3)

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
$V_{IN1(p-p)}$ Input Voltage (Peak-To-Peak)	Single-Ended @ 120 MHz	200		1000	mV
$V_{IN2(p-p)}$ Input Voltage (Peak-To-Peak)	Differential @ 120 MHz	100		1000	mV
f_{SINE} Input Frequency with Sine Wave	$V_{IN} = 600$ mVp-p	30		120	MHz
f_{TTL} Input Frequency with TTL Input		0		120	MHz
dv Minimum Slew Rate of Square Wave Input	$V_{IN} = 600$ mVp-p			100	V/ μ s
V_{OH} Logical "1" Output Voltage	$V_{CC} = \text{Min}, I_{OH} = -10 \mu\text{A}$ $V_{CC} = \text{Min}, I_{OH} = -400 \mu\text{A}$ $V_{CC} = \text{Min}, I_{OH} = -1.6 \text{mA}$	2.9 2.4 2.0			V V V
I_{OS} Output Short-Circuit Current	$V_{CC} = \text{Max}$	-10		-40	mA
V_{OL} Logical "0" Output Voltage	$V_{CC} = \text{Min}$	$I_{OL} = 8 \text{mA DS8629}$		0.5	V
		$I_{OL} = 1 \text{mA DS8626}$		0.4	V
I_{CC} Supply Current	$V_{CC} = \text{Max}$	DS8629	90	135	mA
		DS8626	80	125	mA
Z_{IN} Input Impedance	$V_{IN} = 0.1 V_{p-p}$ to $1 V_{p-p}$ Freq. = 120 MHz	100	200	350	Ω

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, min/max limits apply across the 0°C to 70°C range for the DS8629 and DS8626. All typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.2\text{V}$.

Note 3: All currents into device pins shown as positive, out of device pins negative, all voltage referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Application Hints

OPERATING NOTES

Two ground and two V_{CC} connections are provided separating the ECL and buffer/amplifier stages from the TTL section, isolating the noise transients inherent in the TTL structure. In most cases, shorting the two grounds externally to a good ground plane and the V_{CC} 's to a wide V_{CC} bus will provide sufficient isolation. All components used in the circuit layout should be suitable for the frequencies involved and leads should be kept short to minimize stray inductance. A well by-passed voltage source should be used.

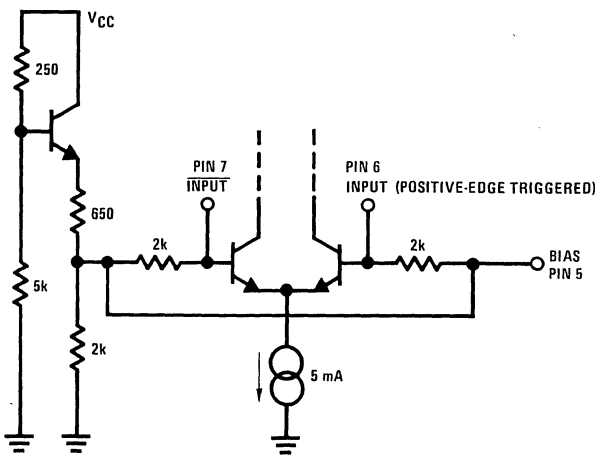
The signal source is usually capacitively coupled to the input. At higher frequencies a $0.01 \mu\text{F}$ input capacitor (C1) is usually sufficient, with larger values used at the lower frequencies. If the input signal is likely to be interrupted, it may be desirable to connect a $100 \text{ k}\Omega$ resistor between one input and ground to stabilize the device. In the single-ended mode, it is preferable to connect the resistor to the unused input. In the differential mode, the resistor can be connected to either input. The addition of the $100 \text{ k}\Omega$ pull-down resistor causes a loss of input sensitivity, but prevents circuit oscillations under no signal (open circuit) conditions. In addition, in the single ended mode, a capacitor of $0.01 \mu\text{F}$ (C2)

should be connected between the unused input and the ground plane to provide a good high frequency bypass. The capacitor should be made larger for lower frequencies.

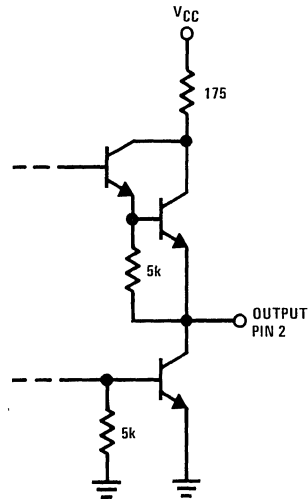
The input waveform may be sinusoidal, but below about 30 MHz the operation of the circuit becomes dependent on the slew rate of the input rather than amplitude. A square wave input with a slew rate of greater than $100 \text{ V}/\mu\text{s}$ will permit correct operation down to lower frequencies, provided the proper input coupling capacitor is provided. If it is desired to use a TTL input signal source, the unused input should have a $10 \text{ k}\Omega$ resistor added to ground and the input coupling capacitor should be eliminated with the TTL source dc coupled to the input.

The device can be used in phase-locked loop applications such as FM radio or other communications bands to prescale the input frequency down to a more usable level. A digital frequency display system can also be derived separately or in conjunction with a phase-locked loop, and it can extend the useful range of many inexpensive frequency counters to 160 MHz (typically).

Input Configuration



Output Configuration



DS8627, DS8628 130/225 MHz Low Power Prescalers

General Description

The DS8627 and DS8628 are low power fixed ratio prescalers which divide by 24 and 20, respectively. The inputs can be driven either single or double-ended and they are buffered, providing 40/100 mVrms input sensitivity. The output provided is open-collector and is capable of interfacing with TTL and CMOS.

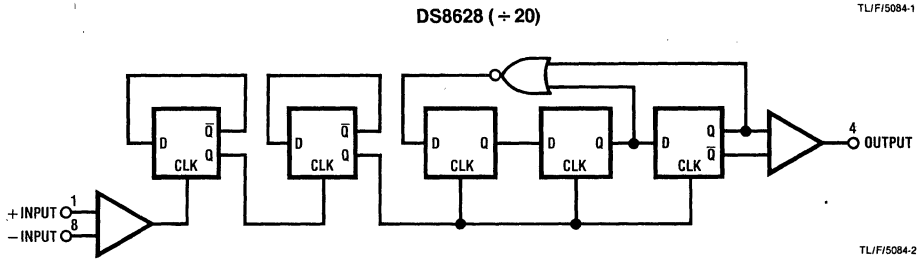
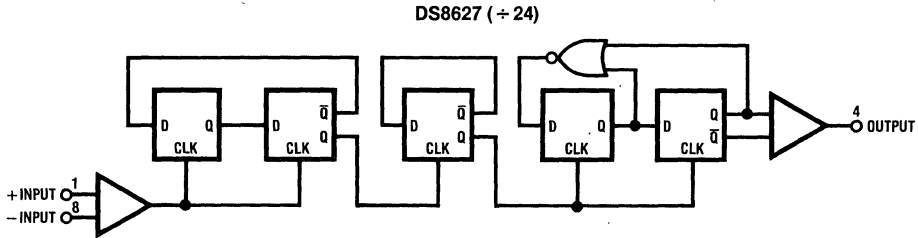
The device can be used in phase-locked loop applications such as FM radio or other communications bands to pre-scale the input frequency down to a more usable level. A digital frequency display system can also be derived

separately or in conjunction with a phase-locked loop, and it can extend the useful range of many inexpensive frequency counters to 225 MHz.

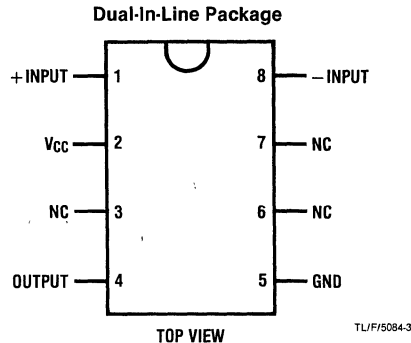
Features

- Input frequency: 130 MHz (-4, -3); 225 MHz (-2, std)
- Low power: 10 mA (-4, -2); 7 mA (-3, std)
- Input sensitivity: 100 mVrms (-4, -3); 40 mVrms (-2, std)

Logic Diagrams



Connection Diagram



Order Number DS8627N or DS8628N (-4, -3, -2)
 See NS Package N08E

Absolute Maximum Ratings (Note 1)

V_{CC} Supply Voltage	7V
V_{IN} Input Voltage	$< V_{CC}$
Open-Collector Output Voltage	7V
Operating Free Air Temperature Range	-30°C to +70°C
Storage Temperature Range	-65°C to +150°C

Recommended Operating Conditions

Symbol	Parameter	Conditions	DS8627-4 DS8628-4		DS8627-3 DS8628-3		DS8627-2 DS8628-2		DS8627 DS8628		Units
			Min	Max	Min	Max	Min	Max	Min	Max	
			V_{CC}	Supply Voltage		4.5	5.5	4.5	5.5	4.5	
f_{MAX}	Toggle Frequency	$V_{IN} = 100$ mVrms	20	130	20	130	20	225	20	225	MHz
V_{IN}	Input Signal Amplitude		100	300	100	300	40	300	40	300	mVrms
V_{SLW}	Slew Rate		20		20		20		20		V/ μ s
I_{OL}	Low Level Output Current			3		3				3	mA

DC Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	DS8627-4 DS8628-4		DS8627-3 DS8628-3		DS8627-2 DS8628-2		DS8627 DS8628		Units
			Min	Max	Min	Max	Min	Max	Min	Max	
			I_{CEX}	Open-Collector High Level Output	Output = 5.5V		100		100		
V_{OL}	Low Level Output Voltage	$V_{CC} = 4.5V$, $I_{OL} = 3$ mA		0.4		0.4		0.4		0.4	V
I_{CC}	Supply Current	$V_{CC} = 5.5V$		10		7		10		7	mA

AC Electrical Characteristics $V_{CC} = 5V \pm 10\%$, $T_A = -30^\circ\text{C}$ to 70°C

Symbol	Parameter	Conditions	Min	Max	Units
R_{IN}	AC Input Resistance	$V_{IN} = 100$ MHz and 50 mVrms	1.0		k Ω
C_{IN}	Input Capacitance		3	10	pF

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -30°C to +70°C temperature range.

Note 3: All currents into device pins are shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Application Hints

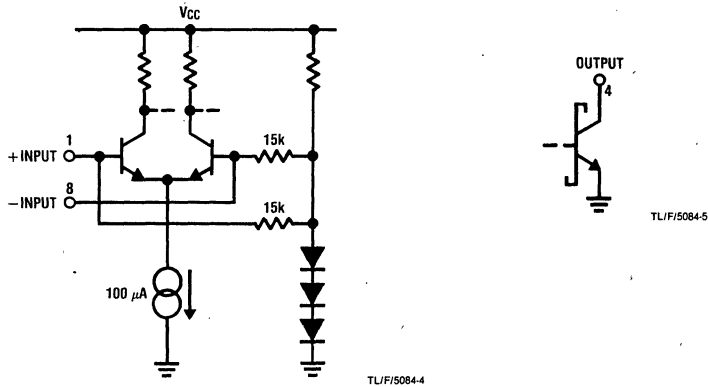
OPERATING NOTES

The signal source is usually capacitively coupled to the input. At higher frequencies a 0.001 μF input capacitor is usually sufficient, with larger values used at the lower frequencies. If the input signal is likely to be interrupted, it may be desirable to connect a 100 k Ω resistor between one input and ground to stabilize the device. In the single-ended mode, it is preferable to connect the resistor to the unused input. In the differential mode, the resistor can be connected to either input. The addition of the 100 k Ω pull-down resistor causes a loss of input sensitivity, but prevents circuit oscillations under no signal (open circuit)

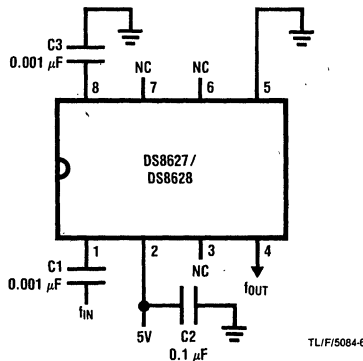
conditions. In addition, in the single ended mode, a capacitor of 0.001 μF should be connected between the unused input and the ground plane to provide a good high frequency bypass. The capacitor should be made larger for lower frequencies.

The input waveform may be sinusoidal, but below about 20 MHz the operation of the circuit becomes dependent on the slew rate of the input rather than amplitude. A square wave input with a slew rate of greater than 20V/ μs will permit correct operation down to lower frequencies, provided the proper input coupling capacitor is provided.

Schematic Diagrams



Typical Application



DS8621 275 MHz/1.2 GHz VHF/UHF Prescaler

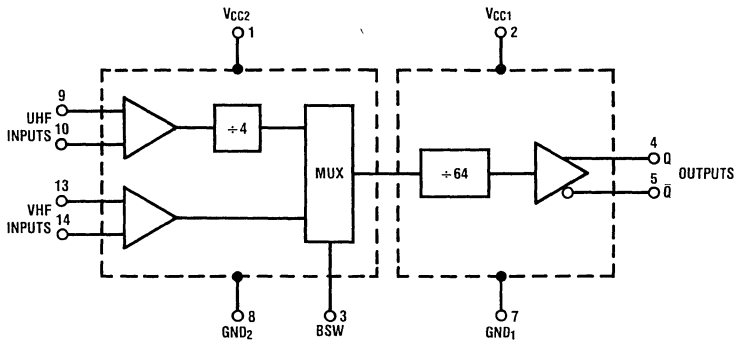
General Description

The DS8621 is a low power, high speed prescaler intended for use in frequency synthesized television tuners. The device performs division by 64 from the VHF input and division by 256 from the UHF input. The VHF and UHF inputs are buffered providing 50 mVrms sensitivity at frequencies in excess of 275 MHz and 1.2 GHz respectively. (The VHF and UHF input signals can be applied either single or double-ended.) The TTL compatible bandswitch (BSW) input selects the VHF inputs when at a low level and the UHF inputs when at a high level. The outputs are complementary ECL structures which have controlled edge-transition rates to minimize spurious harmonic emissions. The device operates from a $5V \pm 10\%$ supply source. V_{CC2} and GND_2 power the VHF and UHF input stages while V_{CC1} and GND_1 power the remainder of the circuit, thus limiting internal feedback.

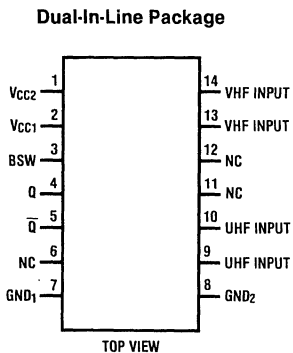
Features

- Broadband operation
- High sensitivity
- Separate VHF and UHF inputs
- Low power
- Pin compatible with RCA (CA3179) and Motorola (MC12071)

Logic Diagram



Connection Diagram



Logic Truth Table

BSW	Input Mode	Modulus
0	VHF	64
1	UHF	256

Order Number DS8621N
See NS Package N14A

Absolute Maximum Ratings (Note 1)

V_{CC1} , Supply Voltage	7V
V_{CC2} , Supply Voltage	7V
Input Voltage	7V
Operating Free Air Temperature Range	-30°C to +70°C
Storage Temperature Range	-65°C to +150°C

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Units
	Supply Voltages				
	V_{CC1}		4.5	5.5	V
	V_{CC2}		4.5	5.5	V
f_{MAX}	Toggle Frequency	$V_{IN} = 100$ mVrms			
	VHF		80	275	MHz
	UHF		80	1200	MHz
V_{IN}	Input Signal Sensitivity				
	VHF	80 MHz-275 MHz	20	500	mVrms
	UHF	80 MHz-450 MHz	100	500	mVrms
		450 MHz-1200 MHz	50	500	mVrms
	Input Slew Rate				
	VHF		20		V/ μ s
	UHF		20		V/ μ s
I_{OH}	High Level Output Current			-300	μ A
I_{OL}	Low Level Output Current			300	μ A

DC Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Max	Units
V_{IH}	High Level BSW Input Voltage	$V_{CC} = 5.5V$	2.0		V
V_{IL}	Low Level BSW Input Voltage	$V_{CC} = 4.5V$		0.8	V
I_I	Max High Level BSW Input Current	$V_{CC} = 4.5V$ $V_{IH} = 7V$		100	μ A
I_{IH}	High Level BSW Input Current	$V_{CC} = 4.5V$ $V_{IH} = 2.7V$		20	μ A
I_{IL}	Low Level BSW Input Current	$V_{CC} = 5.5V$ $V_{IL} = 0.4V$		-100	μ A
	Output Voltage Range	Refer to Output Load Diagram	0.75	1.6	Vp-p
I_{CC}	Supply Current	$V_{CC} = 5.5V$		32.0	mA

AC Electrical Characteristics $V_{CC} = 5V \pm 10\%$, $T_A = -30^\circ\text{C}$ to $+70^\circ\text{C}$

Parameter	Conditions	Min	Max	Units
Output Rise/Fall Time	Refer to Output Load Diagram	40	110	ns

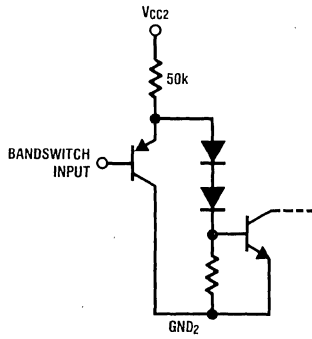
Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -30°C to $+70^\circ\text{C}$ temperature range.

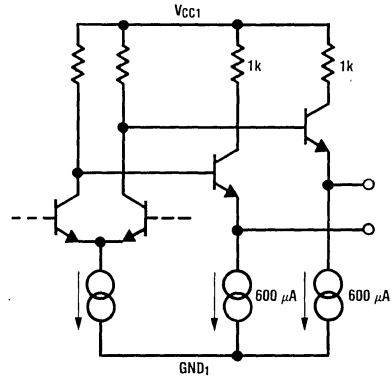
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Typical Input/Output Schematics

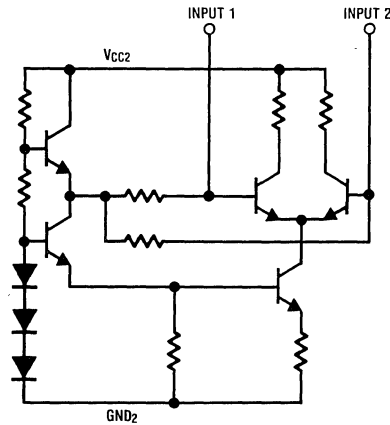
Bandswitch Buffer



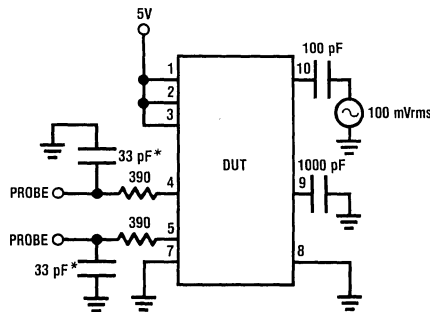
Output Buffer



UHF/VHF Input Buffers



Output Load Diagram



* includes capacitance of probes

DS8622 500 MHz/1.2 GHz Dual Modulus VHF/UHF Prescaler

General Description

The DS8622 is a low power broadband dual modulus prescaler intended for use in frequency synthesized television tuners. The device features separate VHF and UHF buffered inputs, VHF input division by 126 or 128, UHF input division by 252 or 256, TTL compatible bandswitch and modulus control inputs, complementary ECL outputs, and 5V operation.

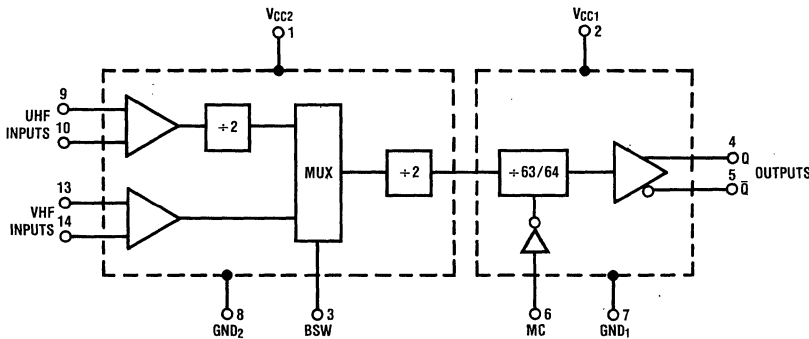
The VHF and UHF inputs cover a frequency range from 80 MHz to 1200 MHz and can be driven either single or double-ended. The bandswitch (BSW) input selects the VHF inputs when at a low level and the UHF inputs when at a high level. The modulus control (MC) input selects division by 126 or 252 when at a high level and division by 128 or 256 when at a low level. The dual modulus feature of this prescaler can provide frequency resolution steps of 3.9 kHz, 7.8 kHz, or 15.6 kHz as shown in the table of Pos-

sible Operating Conditions. The outputs are internally edge-transition controlled to minimize spurious harmonic emissions. The device operates from a standard $5V \pm 10\%$ supply source. V_{CC2} and GND_2 power the VHF and UHF input stages, and V_{CC1} and GND_1 power the remainder of the circuit, thus limiting internal feedback.

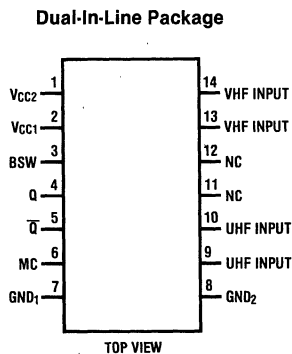
Features

- Broadband operation
- Increased frequency resolution
- High input sensitivity
- Separate VHF and UHF inputs
- Low power

Logic Diagram



Connection Diagram



Logic Truth Table

BSW	MC	Input Mode	Modulus
0	0	VHF	128
0	1	VHF	126
1	0	UHF	256
1	1	UHF	252

Order Number DS8622N
 See NS Package N14A

Absolute Maximum Ratings (Note 1)

V _{CC1} , Supply Voltage	7V	Operating Free Air Temperature Range	-30°C to +70°C
V _{CC2} , Supply Voltage	7V	Storage Temperature Range	-65°C to +150°C
BSW, MC Input Voltage	7V		

Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Units
	Supply Voltages V _{CC1} V _{CC2}		4.5 4.5	5.5 5.5	V V
f _{MAX}	Toggle Frequency VHF UHF	V _{IN} = 100 mVrms	80 80	550 1200	MHz MHz
V _{IN}	Input Signal Sensitivity VHF UHF	80 MHz-550 MHz 80 MHz-550 MHz 550 MHz-1200 MHz	50 100 50	500 500 500	mVrms mVrms mVrms
	Input Slew Rate VHF UHF		20 20		V/μs V/μs
I _{OH}	High Level Output Current			-300	μA
I _{OL}	Low Level Output Current			300	μA

DC Electrical Characteristics (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Max	Units
V _{IH}	High Level Input Voltage (Note 4)	V _{CC} = 5.5V	2.0		V
V _{IL}	Low Level Input Voltage (Note 4)	V _{CC} = 4.5V		0.8	V
I _I	Max Input Current (Note 4)	V _{CC} = 4.5V V _{IH} = 7V		100	μA
I _{IH}	High Level Input Current (Note 4)	V _{CC} = 4.5V V _{IH} = 2.7V		20	μA
I _{IL}	Low Level Input Current (Note 4)	V _{CC} = 5.5V V _{IL} = 0.4V		-100	μA
	Output Voltage Range	Refer to Output Load Diagram	0.75	1.6	Vp-p
I _{CC}	Supply Current			32.0	mA

AC Electrical Characteristics V_{CC} = 5V ± 10%, T_A = -30°C to +70°C

Symbol	Parameter	Conditions	Min	Max	Units
t _{MODULUS}	Modulus Set-Up Time (Note 5)			65	ns
t _{SEL}	BSW Select Time			20	μs
	Output Rise/Fall Time	Refer to Output Load Diagram	40	110	ns

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -30°C to +70°C temperature range.

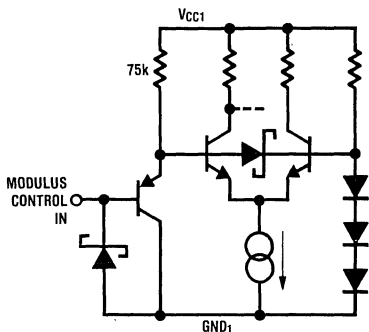
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Applies to BSW and MC inputs.

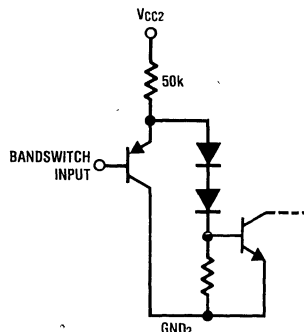
Note 5: t_{MODULUS} = the period of time the modulus control level must be defined prior to the positive transition of the prescale output to ensure proper modulus selection.

Typical Input/Output Schematics

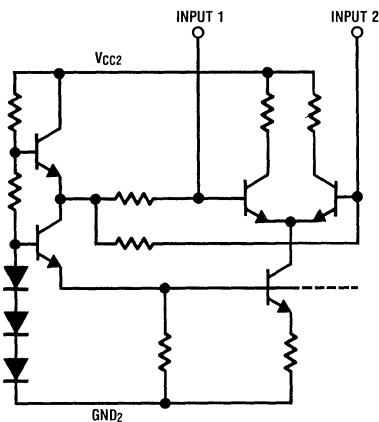
Modulus Control Buffer



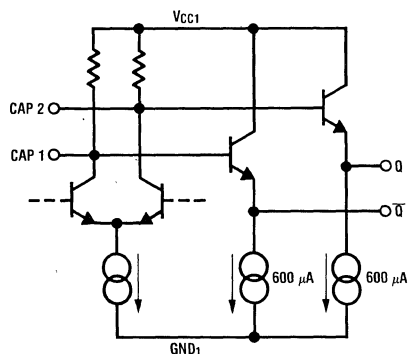
Bandswitch Buffer



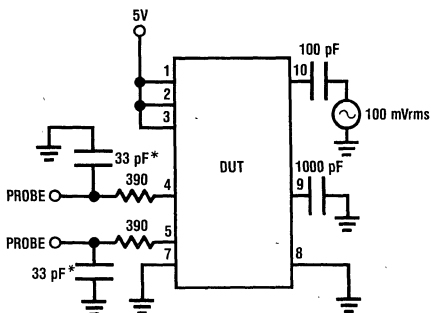
UHF/VHF Input Buffers



Output Buffer



Output Load Diagram



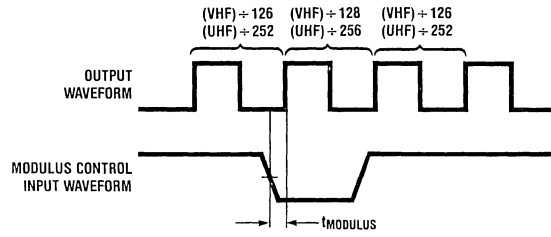
* Includes capacitance of probes.

POSSIBLE OPERATING CONDITIONS

Reference Frequency (kHz)	Mode	Frequency Resolution (kHz)	Min Lock Frequency* (MHz)
15.625	VHF	31.25	124.03125
	UHF	62.5	248.0625
7.8125	VHF	15.625	62.015625
	UHF	31.25	124.03125
3.90625	VHF	7.8125	31.0078
	UHF	15.625	62.015625

* Frequencies obtainable using minimum continuous N code.

Timing Diagram



The modulus control input level is sensed immediately prior to the output low-to-high level transition. The prescaler's modulus value will respond to the change in the modulus control input level immediately *after* that same output low-to-high level transition.

Digital PLL Synthesis

National Semiconductor
Application Note 335
Craig Davis
Tom Mills
Keith Mueller
April 1983



I. System Concepts

INTRODUCTION

Digital tuning systems are fast replacing the conventional mechanical systems in AM/FM and television receivers. The desirability of the digital approach is mainly due to the following features:

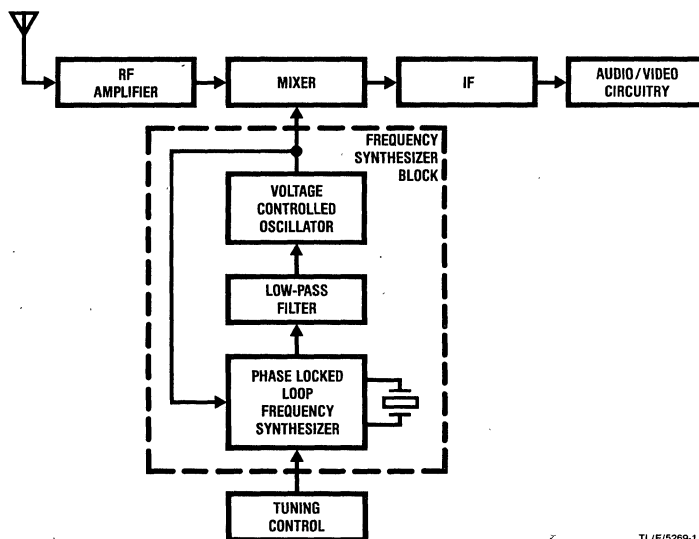
- Precise tuning of station frequencies
- Exact digital frequency display
- Keyboard entry of desired frequency
- Virtually unlimited station memory
- Up/down scanning through the band
- Station "search" (stop on next active station)
- Power on to the last station
- Easy option for time-of-day clock

In addition, recent developments in large scale integrated circuit technology and new varactor diodes for the AM band have made the cost-benefit picture for digital tuning very attractive. System partitioning is extremely important in optimizing this cost-benefit picture, as will be discussed.

SYSTEM DESCRIPTION

A simplified block diagram of a typical digitally tuned receiver is shown in *Figure 1*. Notice this receiver could be one for AM, FM, marine radio, or television; it makes no difference. The frequency synthesizer block generates the local oscillator frequency for the receiver, just as a conventional mechanical tuner would. However, the phase-locked-loop (PLL) acts as an integral frequency multiplier of an accurate crystal controlled reference frequency while the mechanical type provides a continuously variable frequency output with no reference. Some method of controlling the value of the multiplier for channel tuning must be provided. The other RF, IF, and audio/video circuitry will be the same as in the mechanical tuning method.

There are many different ways to partition the frequency synthesizer system to perform the digital tuning function.



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FIGURE 1. Block Diagram of a Digitally Tuned Receiver

PROGRAMMABLE CONTROLLER FUNCTION

The most cost-effective application of different IC process technologies is shown in Figure 2. The controller is separate from the PLL. The controller can be as simple as a mask programmable microcontroller* or as complicated as a high-powered microprocessor system. It can be done most economically with NMOS technology because of the logic density possible and the small size of the RAM/ROM memory cells. It could also be CMOS for extremely low power consumption in standby mode.

BASIC PHASE-LOCKED-LOOP FUNCTION

The DS8906/7/8 series of PLLs utilize a dual-modulus frequency synthesis technique. The reasons for this and the PLL itself will now be discussed.

Figure 3 is a diagram of the most simple phase-locked-loop. A particular reference frequency is generated by a crystal oscillator and some fixed divider, and this goes

into one side of a digital phase comparator. A voltage controlled oscillator (VCO) feeds directly into the other input of the phase comparator. The output of the phase comparator is an error signal which is filtered and fed back to the VCO as a DC control voltage.

In lock, the phase error must be zero, so f_{IN} equals f_{REF} . This system provides only one output frequency, that being equal to the reference frequency.

Figure 4 is basically the same but now a programmable divide-by-N counter is between the VCO and the phase comparator. The input to the phase comparator (f_{IN}) now becomes the output frequency of the VCO (f_{OUT}) divided by N, where N is the division code loaded into the programmable counter. This means f_{OUT}/N must equal f_{REF} . Thus, the VCO output frequency becomes $N \times f_{REF}$, and f_{OUT} can now be changed in integral steps of f_{REF} by merely changing N.

* Such as National's COPS™ family.

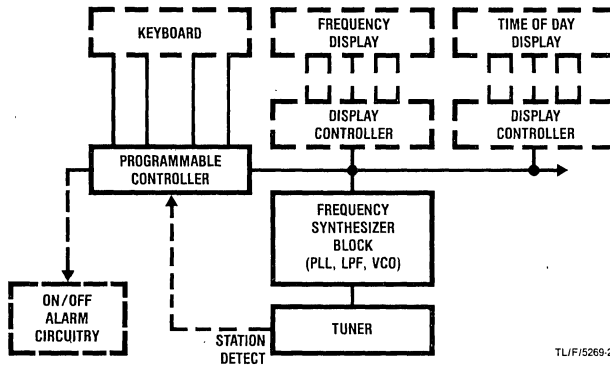


FIGURE 2. System Block Diagram

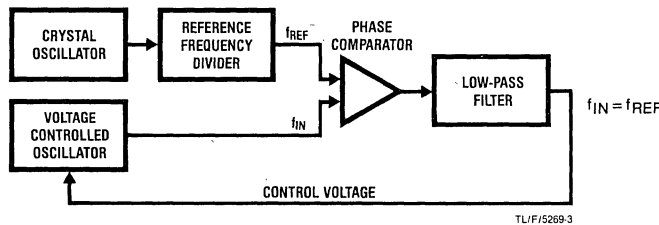


FIGURE 3. Basic Phase-Locked-Loop

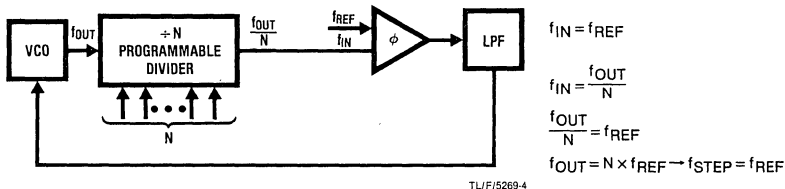


FIGURE 4. Basic PLL Frequency Synthesizer

In applications where the output frequency desired exceeds the maximum clock frequency of available programmable dividers, a common solution is to add a prescaler preceding the programmable divider, as shown in Figure 5. In this case $f_{OUT} = N(M \times f_{REF})$ and so the output frequency step size becomes $M \times f_{REF}$. So, while this technique allows higher frequency operation, it does so at the expense of either increased channel spacing for a given reference frequency, or decreased reference frequency if a specific channel spacing is required. This latter limitation is often undesirable as it can cause increased lock-on time, decreased scanning rates, and sidebands at undesirable frequencies.

Figure 6 shows the basic dual-modulus scheme. Here, a dual-modulus prescaler is substituted for the fixed prescaler and the modulus is controlled by programmable counters. The advantage to this approach is that the step size is again equal to the reference frequency while the prescaling still allows the programmable counters to operate at lower frequencies. As in the fixed prescale technique, only the prescaler needs to be high speed. The DS8906/7/8 prescale by 7/8 for AM and in a similar fashion by 63/64 in FM.

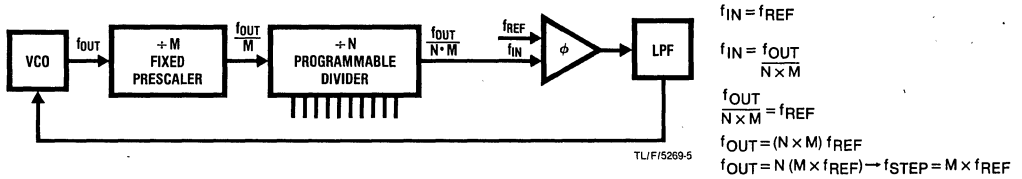


FIGURE 5. PLL Frequency Synthesizer with Fixed Prescaler

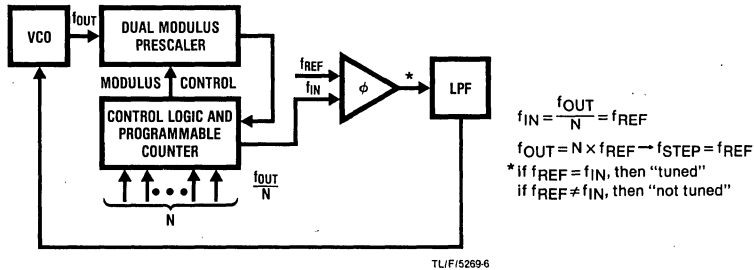


FIGURE 6. Basic Dual-Modulus Frequency Synthesizer

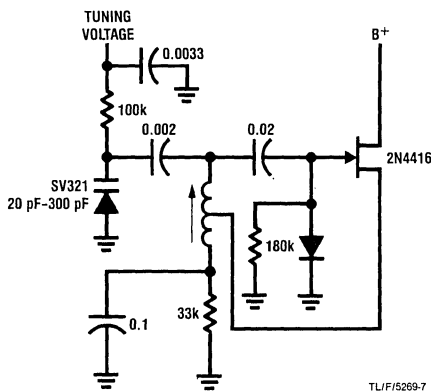
II. Application Hints

VOLTAGE CONTROLLED OSCILLATORS

In all radio and television applications, the voltage controlled oscillator (VCO) is a varactor tuned, LC type of circuit. The LC circuit is used over the various RC current controlled circuits because of their superior noise characteristics. Figure 7 shows a collection of popular VCOs used in radio and television tuners. The AM VCO is a Hartley design chosen for wide tuning range. Commonly used varactors will show a capacitance change of 350 pF at 1V to 20 pF at 8V, which if used in a low capacitance oscillator circuit, can produce a tuning range approaching 3 to 1.

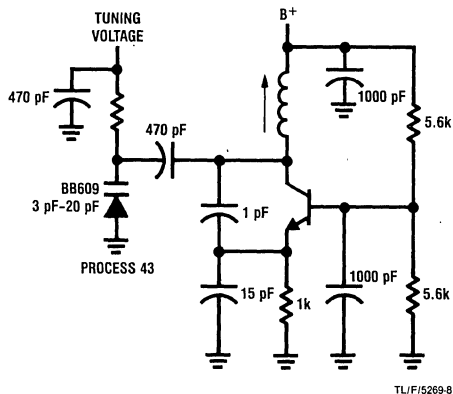
In the higher frequency ranges, above 50 MHz, Colpitts oscillators are used because stray circuit capacitance will be in parallel with desired feedback capacitance and not cause undesirable spurious resonances that might occur with the tapped coil Hartley design. The FM VCO shown is a grounded base design with feedback from collector to emitter. A UHF television oscillator is also shown. It too is a grounded base oscillator, but using a transmission line as the resonant element instead of a coil. The transmission line and tuning capacitors are arranged in π network which offers improved noise characteristics over a parallel tuned circuit. This circuit will tune over almost an octave.

Hartley Oscillator



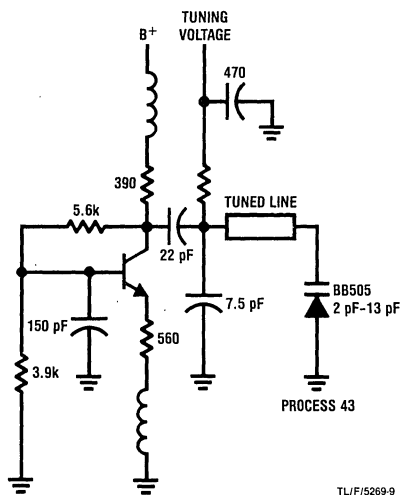
50 kHz ~ 15 MHz VCO
Tuning range = 3:1

Colpitts Oscillator



50 MHz ~ 300 MHz VCO
Tuning range = 2:1

Colpitts Oscillator



500 MHz ~ 1000 MHz VCO
Tuning range = 1.8:1

FIGURE 7. Typical VCO Circuits (Typical Values Shown)

PLL LOOP FILTER CALCULATIONS

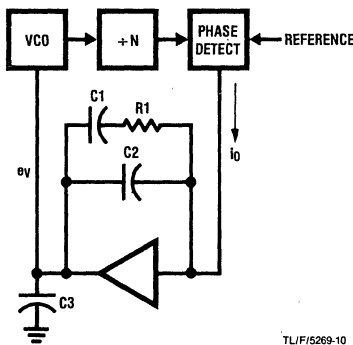
Andrzej Przedpelski, in two articles published in Electronic Design (#19, Sept. 13, 1978 and #10, May 10, 1978) explains how to calculate the three time constants associated with a third order type 2 loop which is typically used with the DS8906/7/8 series. Figure 8 explains his method and shows a sample calculation. His articles illustrate how to calculate three time constants, and plot open loop gain and phase, and closed loop noise response.

It should be noted that VCO gain, K_V , is in terms of radians per second per volt, and phase detector gain, K_D , is in terms of amps per radian. The phase detector gain for the DS8906/7/8 series is $\pm I_{OUT}$ divided by 4π .

Figure 9 illustrates an example calculation of time constants, and a plot of open loop gain and phase based on the preceding analysis.

REFERENCES

1. Manassewitsch V., "Frequency Synthesizers" (Wiley, New York, 1976)
2. Rohde, A. L., "Digital PLL Frequency Synthesizers" (Prentice Hall, Englewood Cliffs, 1983)
3. Egan, W.F., "Frequency Synthesis By Phase Lock" (Wiley, New York, 1981)



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$$T1 = R1C1$$

$$T2 = R1C2$$

$$\frac{e_V}{I_O} = \frac{1 + ST1}{SC1(1 + ST2)}$$

$$G(S) = \frac{K_D K_V}{NS^2 C1} \left(\frac{1 + ST1}{1 + ST2} \right)$$

$$T2 = \frac{1 - \tan \phi \cos \phi}{\omega_O \cos \phi}$$

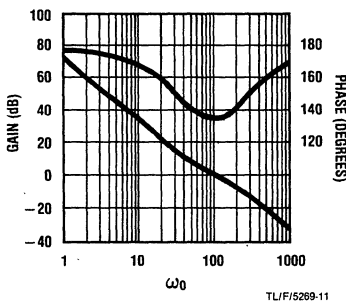
$$T1 = \frac{1}{\omega_O^2 T2}$$

$$C1 = \frac{K_D K_V}{N \omega_O^2} \left(\frac{-\omega_O T1 - 1}{\omega_O T2 + 1} \right)$$

where θ = desired phase margin
 ω_O = loop natural frequency
 \approx closed loop bandwidth

Note: DS8908 op amp requires C3 \approx 1000 pF for compensation.

FIGURE 8. Third Order Type 2 Loop



TL/F/5269-11

VHF loop, running at 100 MHz, ref = 10 kHz

$$K_V = 2.5 \text{ MHz/V} = 15.7 \text{ Mrad/sec/V}$$

$$K_D = \frac{400 \mu\text{A}}{4\pi} = 31.8 \mu\text{A/radian}$$

$$N = \frac{100 \text{ MHz}}{10 \text{ kHz}} = 10,000, \omega_O = 2\pi \times 100 \text{ Hz}$$

$$\theta = 45^\circ \text{ (desired phase margin)}$$

$$T2 = 6.6 \times 10^{-4} \text{ sec}$$

$$T1 = 3.84 \times 10^{-3} \text{ sec}$$

$$C1 = 0.3 \mu\text{F}$$

$$\text{so } R1 = T1/C1 = 13 \text{ k}\Omega$$

$$C2 = T2/R1 = 0.05 \mu\text{F}$$

FIGURE 9. Example of Gain and Phase Calculation

DUAL-MODULUS COUNTING RANGE LIMITATIONS

- Minimum count limitations
- Maximum count limitations

The DS8906/7/8 series PLLs utilize a dual-modulus counting scheme internally based on a 63/64 prescale modulus in FM mode in order that all of the U.S. FM frequency assignments could be reached using a 25 kHz reference. The counter modulus $N = 64A + B$ where B is the 6 least significant bits of N and A is the 7th and greater significant bits of N.

$$N = 64A + B$$

$$N = 64A + \overline{63} - B \quad (B = 63 - \overline{B})$$

$$1 + N = 64A + 63 + 1 - 64\overline{B} + 63\overline{B}$$

$$1 + N = 64(A + 1 - \overline{B}) + 63\overline{B}$$

The last equation is in the final form used internally by the DS8906/7/8. The equation indicates that, if N is loaded into the device, it will solve for N + 1.

The minimum continuous N modulus (code) the equation dictates should occur when $A = \overline{B}$. \overline{B} maximum = 63 implies $A = \overline{62}$, $B = 63$ should be an illegal N + 1 code ($N + 1 = 3969$). However, because this is just inside the lower FM band limits, extra circuitry was added to enable this particular code's operation. The actual minimum N + 1 code for these PLLs thus becomes the case when $A = 61$, $\overline{B} = 61$, $N + 1$ minimum = 3907. There are legitimate N + 1 codes below this 3907 value, however, they are not continuous. (i.e., Starting at 3907 and counting down, one additional code is in error every 63 codes. Thereafter, these erroneous codes are the cases where $A < \overline{B}$.) The sequence of illegal codes is shown in Figure 10.

Loaded Value of N	A	\overline{B}	Status	Actual Locked N + 1 Value
3906	61	61	OK	3907
3905	61	62	illegal	3907
3904	61	63	illegal	3907
3903	60	0	OK	3904
.
.
.
3843	60	60	OK	3844
3842	60	61	illegal	3844
3841	60	62	illegal	3844
3840	60	63	illegal	3844
3839	59	0	OK	3840
.
.
.
3780	59	59	OK	3781
3779	59	60	illegal	3781
3778	59	61	illegal	3781
3777	59	62	illegal	3781
3776	59	63	illegal	3781
3775	58	0	OK	3776
.
.
.
3717	58	58	OK	3718
3716	58	59	illegal	3718
3715	58	59	illegal	3718
3714	58	60	illegal	3718
3713	58	61	illegal	3718
3712	58	63	illegal	3718
3711	57	0	OK	3712
.
.
.

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FIGURE 10. FM Mode Dual-Modulus Counting Below the Minimum Continuous N Code of 3906

Maximum code limits for these dual-modulus PLLs are determined by the N code bit length. The DS8906 and DS8908 have a 14-bit N counter allowing 16,383 counts. The DS8907 has a 13-bit N code length, allowing a maximum N count of 8,191. See *Figure 11* for table operating ranges of the DS8906, DS8907 and DS8908 PLLs.

PLL Loop Bandwidth	300 Hz
Reference Frequency Sidebands	> 60 dB
Signal-to-Noise Ratio	> 50 dB
AM: 30% modulation	> 55 dB
FM: 22.5 kHz deviation	> 55 dB
Switching Speed (one channel)	< 1.5 ms

CONCLUSION

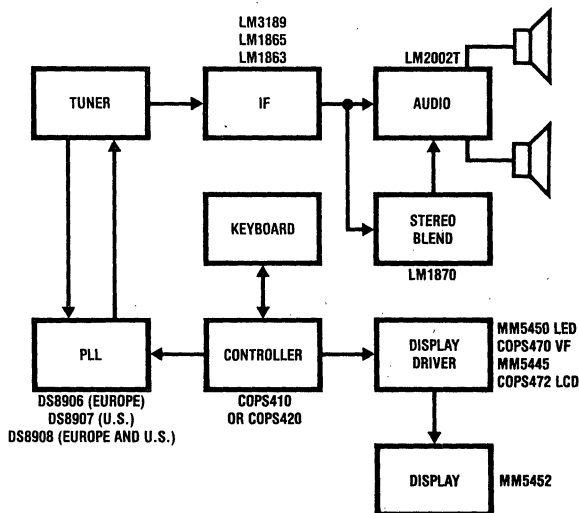
The major application for the DS8906/7/8 PLLs are synthesizers for AM-FM radios, and have been widely accepted in the marketplace. *Figure 12* shows the block diagram of such a radio. In this application the following performance relating to the PLL tuning system is realized.

Product	Input	Ref (Hz)	f _{IN} (Hz)	
			Min*	Max
DS8906	AM	500	24.5k	8.193M
	FM	12.5k	48.8375M	120M
DS8907	AM	10k	490k	15M
	FM	25k	97.675M	120M
DS8908	AM	1k	49k	15M
		9k	441k	15M
		10k	490k	15M
		20k	980k	15M
	FM	1k	3.907M	15M
		9k	35.163M	120M
		10k	39.07M	120M
		20k	78.14M	120M

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*The minimum frequency shown is obtained when the minimum continuous N code is utilized and it assumes the edge rates > 20V/μs.

FIGURE 11. Product Operating Frequency Range



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FIGURE 12. AM-FM Digitally Tuned Radio System



Section 12 Interface Appendices

12

DEVICE	DESCRIPTION	PAGE NUMBER
—	Interface Cross Reference Guide	12-3
AN-336	Understanding Integrated Circuit Package Power Capabilities	12-11
—	Industry Package Cross Reference Guide	12-16

Interface Cross Reference Guide

 National Semiconductor

Device Designation	National's Direct Replacement	National's Closest Replacement
AMD		
AM26LS30DC	DS3691J	
AM26LS30PC	DS3691N	
AM26LS31DC	DS26LS31CJ	
AM26LS31PC	DS26LS31CN	
AM26LS32DC	DS26LS32ACJ	DS26LS32CJ
AM26LS32PC	DS26LS32ACN	DS26LS32CN
AM26LS33DC	DS26LS33ACJ	DS26LS33CJ
AM26LS33PC	DS26LS33ACN	DS26LS33CN
AM26S10DC	DS26S10J	
AM26S10PC	DS26S10N	
AM26S11DC	DS26S11J	
AM26S11PC	DS26S11N	
AM26S12DC		DS8838J
AM26S12PC		DS8838N
AM2965DC		DP84240J
AM2965PC		DP84240N
AM2966DC		DP84244J
AM2966PC		DP84244N
N8T26AB	DS8T26AN	
N8T26AF	DS8T26AJ	
N8T28F	DS8T28J	
N8T28N	DS8T28N	
D8212	DP8212J	
P8212	DP8212N	
D8216	DP8216J	
P8216	DP8216N	
D8224	DP8224J	
AM8224PC	DP8224N	
D8226	DP8226J	
P8226	DP8226N	
AM8228PC	DP8228N	
D8228	DP8228J	
AM8238PC	DP8238N	
D8238	DP8238J	
DP8303J	DP8303J	
DP8303N	DP8303N	
DP8304BJ	DP8304BJ	
DP8304BN	DP8304BN	
DP8307J	DP8307J	
DP8307N	DP8307N	
DP8308J	DP8308J	
DP8308N	DP8308N	
DS8838J	DS8838J	
DS8838N	DS8838N	

The manufacturer's most current data sheets take precedence over this guide.



Interface Cross Reference Guide (Continued)

NATIONAL'S INTERFACE
 TO
 FAIRCHILD

Device Designation	National's Direct Replacement	National's Closest Replacement
FAIRCHILD		
μA1488DC	DS1488J	
μA1488PC	DS1488N	
μA1489ADC	DS1489AJ	
μA1489APC	DS1489AN	
μA1489DC	DS1489J	
μA1489PC	DS1489N	
μA3680DC	DS3680J	
μA3680PC	DS3680N	
75107ADC	DS75107J	
75107APC	DS75107N	
75107BDC		DS75107J
75107BPC		DS75107N
75108ADC	DS75108J	
75108APC	DS75108N	
75108BDC		DS75108J
75108BPC		DS75108N
75150RC	DS75150J-8	
75150TC	DS75150N	
75154DC	DS75154J	
75154PC	DS75154N	
75450BDC	DS75450J	
75450BPC	DS75450N	
75451ARC	DS75451J-8	
75451ATC	DS75451N	
75451BRC	DS75451J-8	
75451BTC	DS75451N	
75452ARC	DS75452J-8	
75452ATC	DS75452N	
75452BRC	DS75452J-8	
75452BTC	DS75452N	
75453ARC	DS75453J-8	
75453ATC	DS75453N	
75453BRC	DS75453J-8	
75453BTC	DS75453N	
75461RC	DS75461J-8	
75461TC	DS75461N	
75462RC	DS75462J-8	
75462TC	DS75462N	
75471TC		DS3611N
75472TC		DS3612N
75491PC	DS75491N	
75492PC	DS75492N	
75492APC		DS75492N
μA8T26ADC	DS8T26AJ	
μA8T26APC	DS8T26AN	
μA8T28DC	DS8T28J	
μA8T28PC	DS8T28N	
9614DC	DS75114J	
9614PC	DS75114N	
9615DC	DS75115J	
9615PC	DS75115N	
9616DC		DS1488J
9616PC		DS1488N
9617DC		DS1489AJ
9617DC		DS1489J
9617PC		DS75154N

Device Designation	National's Direct Replacement	National's Closest Replacement
9636ARC		DS3691J
9636ATC		DS3691N
9637ARC		DS3486J
9637ATC		DS3486N
9640DC	DS26S10J	
9640PC	DS26S10N	
9643PC		DS75322N
9643TC		DS75322N
9645DC		DS3245J
9645PC		DS3245N

The manufacturer's most current data sheets take precedence over this guide.

Interface Cross Reference Guide (Continued)

Device Designation	National's Direct Replacement	National's Closest Replacement
INTEL		
D3245	DS3245J	
D8212	DP8212J	
P8212	DP8212N	
D8216	DP8216J	
P8216	DP8216N	
D8224	DP8224J	
D8224	DP8224N	
D8226	DP8226J	
P8226	DP8226N	
D8228	DP8228J	
D8228	DP8228N	
D8238	DP8238J	
P8238	DP8238N	
D8286	DP8304BJ	
P8286	DP8304BN	
D8287	DP8303J	
P8287	DP8303N	

The manufacturer's most current data sheets take precedence over this guide.



Interface Cross Reference Guide (Continued)

Device Designation	National's Direct Replacement	National's Closest Replacement
MMI		
74S408N	DP8408N	
74S409N	DP8409N	
74S780N	DP8400N	

The manufacturer's most current data sheets take precedence over this guide.

NATIONAL'S INTERFACE

TO

MMI

Interface Cross Reference Guide (Continued)



Device Designation	National's Direct Replacement	National's Closest Replacement	Device Designation	National's Direct Replacement	National's Closest Replacement
MOTOROLA					
MMH0026CG	DS0026CH	DS0026CG	MC75125P	DS75125N	
MMH0026CL	DS0026CJ		MC75127L	DS75127J	
MMH0026CN	DS0026CN		MC75127P	DS75127N	
MMH0026CP1	DS0026CN		MC75128L	DS75128J	
MMH0026G	DS0026H		MC75128P	DS75128N	
MMH0026L	DS0026J		MC75129L	DS75129J	
MC12015P	DS8615N		MC75129P	DS75129N	
MC12016P	DS8616N		MC75325L	DS75325J	
MC12017P	DS8617N		MC75491P	DS75491N	
MC12071P	DS8621N		MC75492P	DS75492N	
MC1472P1		DS3612N	MC8T13L	DS75121J	
MC1472P1		DS3632N	MC8T13P	DS75121N	
MC1472U		DS3612J-8	MC8T14L	DS75122J	
MC1472U		DS3632J-8	MC8T14P	DS75122N	
MC1488L	DS1488J		MC8T23L	DS75123J	
MC1488P	DS1488N		MC8T23P	DS75123N	
MC1489AL	DS1489AJ		MC8T24L	DS75124J	
MC1489AP	DS1489AN		MC8T24P	DS75124N	
MC1489L	DS1489J		MC8T26AL	DS8T26AJ	DS8834J
MC1489P	DS1489N		MC8T26AP	DS8T26AN	DS8834N
AM26LS31DC	DS26LS31CJ		MC8T28L	DS8T28J	
AM26LS31PC	DS26LS31CN		MC8T28P	DS8T28N	
MC26S10L	DS26S10J		DS8641N	DS8641N	
MC26S10P	DS26S10N		DS8641J	DS8641N	
MC3430L	DS3651J				
MC3430P	DS3651N				
MC3431L		DS3651J			
MC3431P		DS3651N			
MC3432L	DS3653J				
MC3432P	DS3653N				
MC3433L		DS3653J			
MC3433P		DS3653N			
MC3437L	DS8837J				
MC3437P	DS8837N				
MC3438L	DS8838J				
MC3438P	DS8838N				
MC3450L		DS3650J			
MC3450P		DS3650N			
MC3451P		DS3451N			
MC3452P	DS3652N				
MC3486L	DS3486J				
MC3486P	DS3486N				
MC3487L	DS3487J				
MC3487P	DS3487N				
MC3490P		DS8887N			
MC3491P		DS8889N			
MC3494P		DS8897N			
MC6880AL	DS8T26AJ				
MC6880AP	DS8T26AN				
MC6889L	DS8T28J				
MC6889P	DS8T28N				
MC75107L	DS75107J				
MC75107P	DS75107N				
MC75108L	DS75108J				
MC75108P	DS75108N				
MC75125L	DS75125J				

MOTOROLA
TO
NATIONAL'S INTERFACE

The manufacturer's most current data sheets take precedence over this guide.

Interface Cross Reference Guide (Continued)

NATIONAL'S INTERFACE
TO
SIGNETICS

Device Designation	National's Direct Replacement	National's Closest Replacement
SIGNETICS		
MC1488F	DS1488J	
MC1488N	DS1488N	
MC1489AN	DS1489AN	
MC1489AF	DS1489AJ	
MC1489F	DS1489J	
MC1489N	DS1489N	
NE582F		DS75494J
NE582N		DS75494N
75S107F		DS75107J
75S107N		DS75107N
75S108F		DS75108J
75S108N		DS75108N
75S207F		DS75207J
75S207N		DS75207N
75S208F		DS75208J
75S208N		DS75208N
N8T13F	DS75121J	
N8T13N	DS75121N	
N8T14F	DS75122J	
N8T14N	DS75122N	
N8T15F		DS75150J-8
N8T15N		DS75150N
N8T23F	DS75123J	
N8T23N	DS75123N	
N8T24F	DS75124J	
N8T24N	DS75124N	
N8T26AF	DS8T26AJ	
N8T26AN	DS8T26AN	
N8T28F	DS8T28J	
N8T28N	DS8T28N	
N8T34F	DS8834J	
N8T34N	DS8834N	
N8T37F	DS8837J	
N8T37N	DS8837N	
N8T38F	DS8838J	
N8T38N	DS8838N	
N8T380F	DS8836J	DS8640J
N8T380N	DS8836N	DS8640N
*DS8820AF	DS8820AJ	
*DS8820AN	DS8820AN	
*DS8820F	DS8820J	
*DS8820N	DS8820N	
*DS8830F	DS8830J	
*DS8830N	DS8830N	
*DS8880F	DS8880J	
*DS8880N	DS8880N	

The manufacturer's most current data sheets take precedence over this guide.
 *Signetics has announced plans to obsolete these products.

Device Designation	National's Direct Replacement	National's Closest Replacement
SPRAGUE		
UDN3611H	DS3611J-8	
UDN3611M	DS3611N	
UDN3612H	DS3612J-8	
UDN3612M	DS3612N	
UDN3613H	DS3613J-8	
UDN3613M	DS3613N	
UDN3614H	DS3614J-8	
UDN3614M	DS3614N	

the manufacturer's most current data sheets take precedence over this guide.



Device Designation	National's Direct Replacement	National's Closest Replacement	Device Designation	National's Direct Replacement	National's Closest Replacement
TEXAS INSTRUMENTS					
MC1488J	DS1488J		SN75189AN	DS1489AN	
MC1488N	DS1488N		SN75189J	DS1489J	
MC1489AJ	DS1489AJ		SN75189N	DS1489N	
MC1489AN	DS1489AN		SN75207BN	DS75207N	
MC1489J	DS1489J		SN75207J		DS75207J
MC1489N	DS1489N		SN75208BJ	DS75208J	
AM26LS31CJ	DS26LS31CJ		SN75208J		DS75208J
AM26LS31CN	DS26LS31CN		SN75208N		DS75208N
AM26LS32ACJ	DS26LS32ACJ	DS26LS32CJ	SN75325J	DS75325J	
AM26LS32ACN	DS26LS32ACN	DS26LS32CN	SN75325N	DS75325N	
AM26LS33AJ	DS26LS33ACJ	DS26LS33CJ	SN75361AJG	DS75361J-8	
AM26LS33AN	DS26LS33ACN	DS26LS33CN	SN75361AP	DS75361N	
AM26S10CJ	DS26S10J		SN75365J	DS75365J	
AM26S10CN	DS26S10N		SN75365N	DS75365N	
AM26S11CJ	DS26S11J		SN75369J		DS0026CJ-8
AM26S11CN	DS26S11N		SN75369N		DS0026CN
MC3486J	DS3486J		SN75437ANE	DS3658N	
MC3486N	DS3486N		SN75437NE	DS3658N	
MC3487J	DS3487J		SN75450BJ	DS75450J	
MC3487N	DS3487N		SN75450BN	DS75450N	
SN74LS424J	DP8224J		SN75451BJG	DS75451J-8	
SN74LS424N	DP8224N		SN75451BP	DS75451N	
SN74S412J	DP8212J		SN75452BJG	DS75452J-8	
SN74S412N	DP8212N		SN75452BP	DS75452N	
SN74S428N	DP8228N		SN75453BJG	DS75453J-8	
SN74S436N	DS36149N		SN75453BP	DS75453N	
SN74S437N	DS36179N		SN75454BJG	DS75454J-8	
SN74S438N	DP8238N		SN75454BP	DS75454N	
SN75107AJ		DS75107J	SN75461JG	DS75461J-8	
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SN75107BN	DS75107N		SN75462P	DS75462N	
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SN75114J	DS75114J		SN75472JG		DS3612J-8
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SN75115J	DS75115J		SN75473JG		DS3613J-8
SN75115N	DS75115N		SN75473P		DS3613N
SN75121J	DS75121J		SN75474JG		DS3614J-8
SN75121N	DS75121N		SN75474P		DS3614N
SN75122J	DS75122J		SN75477JG		DS3612J-8
SN75122N	DS75122N		SN75477P		DS3612N
SN75123J	DS75123J		SN75480N	DS8880N	
SN75123N	DS75123N		SN75491AN		DS75491N
SN75124J	DS75124J		SN75491N	DS75491N	
SN75124N	DS75124N		SN75492AN		DS75492N
SN75125J	DS75125J		SN75492J	DS75492J	
SN75125N	DS75125N		SN75492N	DS75492N	
SN75127J	DS75127J		SN75494N		DS75494N
SN75127N	DS75127N		N8T13J	DS75121J	
SN75128J	DS75128J		N8T13N	DS75121N	
SN75128N	DS75128N		N8T14J	DS75122J	
SN75129J	DS75129J		N8T14N	DS75122N	
SN75129N	DS75129N		N8T23J	DS75123J	
SN75150J	DS75150J-8		N8T23N	DS75123N	
SN75150N	DS75150N		N8T24J	DS75124J	
SN75154J	DS75154J		N8T24N	DS75124N	
SN75154N	DS75154N		N8T26AJ	DS8T26AJ	
SN75160N	DS75160AN		N8T26AN	DS8T26AN	
SN75161N	DS75161AN		DS8820AJ	DS8820AJ	
SN75161AN	DS75161AN		DS8820AN	DS8820AN	
SN75162N	DS75162AN		DS8830J	DS8830J	
SN75162AN	DS75162AN		DS8830N	DS8830N	
SN75182J	DS8820AJ		DS8831J	DS8831J	
SN75182N	DS8820AN		DS8831N	DS8831N	
SN75183J	DS8830J		DS8832J	DS8832J	
SN75183N	DS8830N		DS8832N	DS8832N	
SN75188J	DS1488J				
SN75188N	DS1488N				
SN75189AJ	DS1489AJ				

TEXAS INSTRUMENTS **TO** **NATIONAL'S INTERFACE**

The manufacturer's most current data sheets take precedence over this guide.

Understanding Integrated Circuit Package Power Capabilities

National Semiconductor
Application Note 336
Charles Carinalli
Josip Huljev
March 1983



INTRODUCTION

The short and long term reliability of National Semiconductor's interface circuits, like any integrated circuit, is very dependent on its environmental condition. Beyond the mechanical/environmental factors, nothing has a greater influence on this reliability than the electrical and thermal stress seen by the integrated circuit. Both of these stress issues are specifically addressed on every interface circuit data sheet, under the headings of Absolute Maximum Ratings and Recommended Operating Conditions.

However, through application calls, it has become clear that electrical stress conditions are generally more understood than the thermal stress conditions. Understanding the importance of electrical stress should never be reduced, but clearly, a higher focus and understanding must be placed on thermal stress. Thermal stress and its application to interface circuits from National Semiconductor is the subject of this application note.

FACTORS AFFECTING DEVICE RELIABILITY

Figure 1 shows the well known "bathtub" curve plotting failure rate versus time. Similar to all system hardware (mechanical or electrical) the reliability of interface integrated circuits conform to this curve. The key issues associated with this curve are infant mortality, failure rate, and useful life.

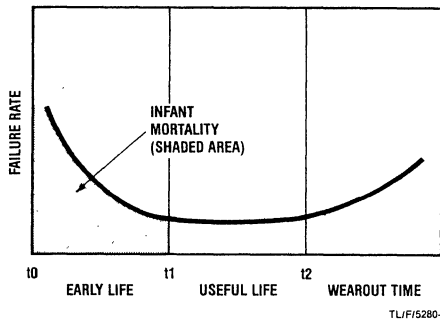


FIGURE 1. Failure Rate vs Time

Infant mortality, the high failure rate from time t0 to t1 (early life), is greatly influenced by system stress conditions other than temperature, and can vary widely from one application to another. The main stress factors that contribute to infant mortality are electrical transients and noise, mechanical maltreatment and excessive temperatures. Most of these failures are discovered in device test, burn-in, card assembly and handling, and initial system test and operation. Although important, much literature is available on the subject of infant mortality in integrated circuits and is beyond the scope of this application note.

Failure rate is the number of devices that will be expected to fail in a given period of time (such as, per million hours). The mean time between failure (MTBF) is the average time (in hours) that will be expected to elapse after a unit has failed before the next unit failure will occur. These two primary "units of measure" for device reliability are inversely related:

$$MTBF = \frac{1}{\text{Failure Rate}}$$

Although the "bathtub" curve plots the overall failure rate versus time, the useful failure rate can be defined as the percentage of devices that fail per-unit-time during the flat portion of the curve. This area, called the useful life, extends between t1 and t2 or from the end of infant mortality to the onset of wearout. The useful life may be as short as several years but usually extends for decades if adequate design margins are used in the development of a system.

Many factors influence useful life including: pressure, mechanical stress, thermal cycling, and electrical stress. However, die temperature during the device's useful life plays an equally important role in triggering the onset of wearout.

FAILURE RATES vs TIME AND TEMPERATURE

The relationship between integrated circuit failure rates and time and temperature is a well established fact. The occurrence of these failures is a function which can be represented by the Arrhenius Model. Well validated and predominantly used for accelerated life testing of integrated circuits, the Arrhenius Model assumes the degradation of a performance parameter is linear with time and that MTBF is a function of temperature stress. The temperature dependence is an exponential function that defines the probability of occurrence. This results in a formula for expressing the lifetime or MTBF at a given temperature stress in relation to another MTBF at a different temperature. The ratio of these two MTBFs is called the acceleration factor F and is defined by the following equation:

$$F = \frac{X1}{X2} = \exp \left[\frac{E}{K} \left(\frac{1}{T2} - \frac{1}{T1} \right) \right]$$

Where: X1 = Failure rate at junction temperature T1
X2 = Failure rate at junction temperature T2
T = Junction temperature in degrees Kelvin
E = Thermal activation energy in electron volts (ev)
K = Boltzman's constant

However, the dramatic acceleration effect of junction temperature (chip temperature) on failure rate is illustrated in a plot of the above equation for three different activation energies in *Figure 2*. This graph clearly demonstrates the importance of the relationship of junction temperature to device failure rate. For example, using the 0.99 eV line, a 30 degree rise in junction temperature, say from 130°C to 160°C, results in a 10 to 1 increase in failure rate.

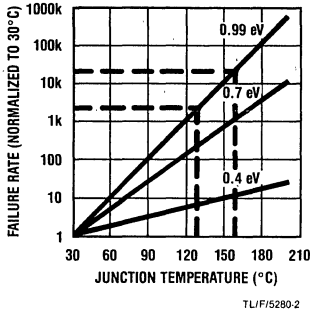


FIGURE 2. Failure Rate as a Function of Junction Temperature

DEVICE THERMAL CAPABILITIES

There are many factors which affect the thermal capability of an integrated circuit. To understand these we need to understand the predominant paths for heat to transfer out of the integrated circuit package. This is illustrated by *Figures 3 and 4*.

Figure 3 shows a cross-sectional view of an assembled integrated circuit mounted into a printed circuit board.

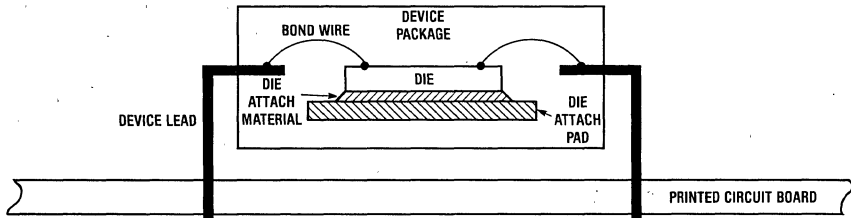


FIGURE 3. Integrated Circuit Soldered into a Printed Circuit Board (Cross-Sectional View)

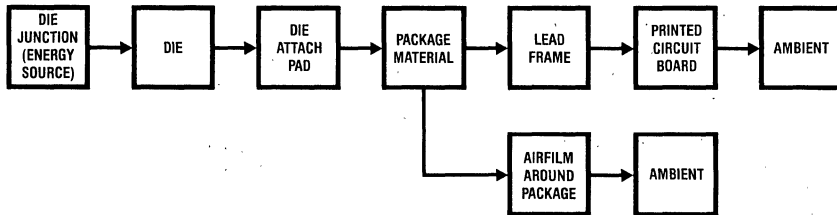


FIGURE 4. Thermal Flow (Predominant Paths)

Figure 4 is a flow chart showing how the heat generated at the power source, the junctions of the integrated circuit, flows from the chip to the ultimate heat sink, the ambient environment. There are two predominant paths. The first is from the die to the die attach pad to the surrounding package material to the package lead frame to the printed circuit board and then to the ambient. The second path is from the package directly to the ambient air.

Improving the thermal characteristics of any stage in the flow chart of *Figure 4* will result in an improvement in device thermal characteristics. However, grouping all these characteristics into one equation determining the overall thermal capability of an integrated circuit/package/environmental condition is possible. The equation that expresses this relationship is:

$$T_J = T_A + P_D (\theta_{JA})$$

- Where: T_J = Die junction temperature
- T_A = Ambient temperature in the vicinity of the device
- P_D = Total power dissipation (in watts)
- θ_{JA} = Thermal resistance junction-to-ambient

θ_{JA} , the thermal resistance from device junction-to-ambient temperature, is measured and specified by the manufacturers of integrated circuits. National Semiconductor utilizes special vehicles and methods to measure and monitor this parameter. All interface circuit data sheets specify the thermal characteristics and capabilities of the packages available for a given device under specific conditions—these package power ratings directly relate to thermal resistance junction-to-ambient or θ_{JA} .

Although National provides these thermal ratings, it is critical that the end user understand how to use these numbers to improve thermal characteristics in the development of his system using interface components.

DETERMINING DEVICE OPERATING JUNCTION TEMPERATURE

From the above equation the method of determining actual worst-case device operating junction temperature becomes straightforward. Given a package thermal characteristic, θ_{JA} , worst-case ambient operating temperature, $T_A(\text{max})$, the only unknown parameter is device power dissipation, P_D . In calculating this parameter, the dissipation of the integrated circuit due to its own supply has to be considered, the dissipation within the package due to the external load must also be added. The power associated with the load in a dynamic (switching) situation must also be considered. For example, the power associated with an inductor or a capacitor in a static versus dynamic (say, 1 MHz) condition is significantly different.

The junction temperature of a device with a total package power of 600 mW at 70°C in a package with a thermal resistance of 63°C/W is 108°C:

$$T_J = 70^\circ\text{C} + (63^\circ\text{C/W}) \times (0.6\text{W}) = 108^\circ\text{C}$$

The next obvious question is, how safe is 108°C?

MAXIMUM ALLOWABLE JUNCTION TEMPERATURES

What is an acceptable maximum operating junction temperature is in itself somewhat of a difficult question to answer. Many companies have established their own standards based on corporate policy. However, the semiconductor industry has developed some defacto standards based on the device package type. These have been well accepted as numbers that relate to reasonable (acceptable) device lifetimes, thus failure rates.

National Semiconductor has adopted these industry-wide standards. For devices fabricated in a molded package, the maximum allowable junction temperature is 150°C. For these devices assembled in ceramic or cavity DIP packages, the maximum allowable junction temperature is 175°C. The numbers are different because of the differences in package types. The thermal strain associated with the die package interface in a cavity package is much less than that exhibited in a molded package where the integrated circuit chip is in direct contact with the package material.

Let us use this new information and our thermal equation to construct a graph which displays the safe thermal (power) operating area for a given package type. *Figure 5* is an example of such a graph. The end points of this graph are easily determined. For a 16-pin molded package, the maximum allowable temperature is 150°C; at this point no power dissipation is allowable. The power capability at 25°C is 1.98W as given by the following calculation:

$$P_{D@25^\circ\text{C}} = \frac{T_J(\text{max}) - T_A}{\theta_{JA}} = \frac{150^\circ\text{C} - 25^\circ\text{C}}{63^\circ\text{C/W}} = 1.98\text{W}$$

The slope of the straight line between these two points is minus the inversion of the thermal resistance. This is referred to as the derating factor.

$$\text{Derating Factor} = -\frac{1}{\theta_{JA}}$$

As mentioned, *Figure 5* is a plot of the safe thermal operating area for a device in a 16-pin molded DIP. As long as the intersection of a vertical line defining the maximum ambient temperature (70°C in our previous example) and maximum device package power (600 mW) remains below the maximum package thermal capability line the junction temperature will remain below 150°C—the limit for a molded package. If the intersection of ambient temperature and package power falls on this line, the maximum junction temperature will be 150°C. Any intersection that occurs above this line will result in a junction temperature in excess of 150°C and is not an appropriate operating condition.

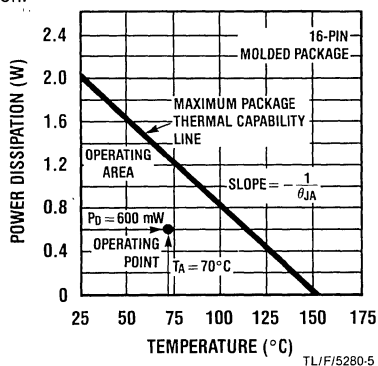


FIGURE 5. Package Power Capability vs Temperature

The thermal capabilities of all interface circuits are expressed as a power capability at 25°C still air environment with a given derating factor. This simply states, for every degree of ambient temperature rise above 25°C, reduce the package power capability stated by the derating factor which is expressed in mW/°C. For our example—a θ_{JA} of 63°C/W relates to a derating factor of 15.9 mW/°C.

FACTORS INFLUENCING PACKAGE THERMAL RESISTANCE

As discussed earlier, improving any portion of the two primary thermal flow paths will result in an improvement in overall thermal resistance junction-to-ambient. This section discusses those components of thermal resistance that can be influenced by the manufacturer of the integrated circuit. It also discusses those factors in the overall thermal resistance that can be impacted by the end user of the integrated circuit. Understanding these issues will go a long way in understanding chip power capabilities and what can be done to insure the best possible operating conditions and, thus, best overall reliability.

Die Size

Figure 6 shows a graph of our 16-pin DIP thermal resistance as a function of integrated circuit die size. Clearly, as the chip size increases the thermal resistance decreases—this relates directly to having a larger area with which to dissipate a given power.

Lead Frame Material

Figure 7 shows the influence of lead frame material (both die attach and device pins) on thermal resistance. This graph compares our same 16-pin DIP with a copper lead frame, a Kovar lead frame, and finally an Alloy 42 type lead frame—these are lead frame materials commonly used in the industry. Obviously the thermal conductivity of the lead frame material has a significant impact in package power capability. Molded interface circuits from National Semiconductor use the copper lead frame exclusively.

Board vs Socket Mount

One of the major paths of dissipating energy generated by the integrated circuit is through the device leads. As a result of this, the graph of Figure 8 comes as no surprise. This compares the thermal resistance of our 16-pin package soldered into a printed circuit board (board mount) compared to the same package placed in a socket (socket mount). Adding a socket in the path between the PC board and the device adds another stage in the thermal flow path, thus increasing the overall thermal resistance. The thermal capabilities of National Semiconductor's interface circuits are specified assuming board mount conditions. If the devices are placed in a socket the thermal capabilities should be reduced by approximately 5% to 10%.

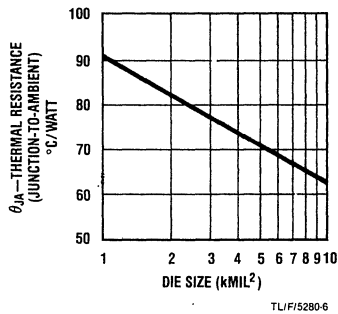


FIGURE 6. Thermal Resistance vs Die Size

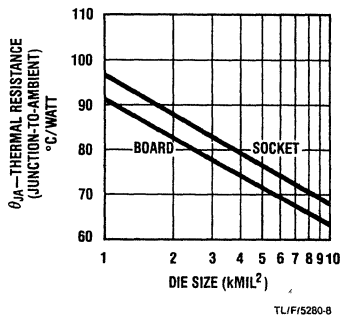


FIGURE 8. Thermal Resistance vs Board or Socket Mount

Air Flow

When a high power situation exists and the ambient temperature cannot be reduced, the next best thing is to provide air flow in the vicinity of the package. The graph of Figure 9 illustrates the impact this has on thermal resistance. This graph plots the relative reduction in thermal resistance normalized to the still air condition for our 16-pin molded DIP. The thermal ratings on National Semiconductor's interface circuits data sheets relate to the still air environment.

Other Factors

A number of other factors influence thermal resistance. The most important of these is using thermal epoxy in mounting ICs to the PC board and heat sinks. Generally these techniques are required only in the very highest of power applications.

Some confusion exists between the difference in thermal resistance junction-to-ambient (θ_{JA}) and thermal resistance junction-to-case (θ_{JC}). The best measure of actual junction temperature is the junction-to-ambient number since nearly all systems operate in an open air environment. The only situation where thermal resistance junction-to-case is important is when the entire system is immersed in a thermal bath and the environmental temperature is indeed the case temperature. This is only used in extreme cases and is the exception to the rule and, for this reason, is not addressed in this application note.

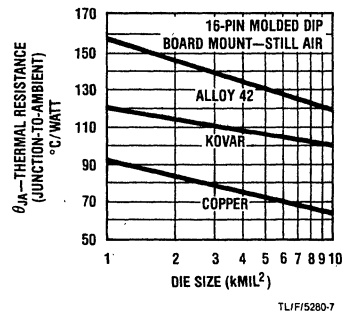


FIGURE 7. Thermal Resistance vs Lead Frame Material

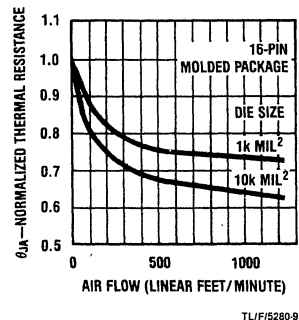


FIGURE 9. Thermal Resistance vs Air Flow

NATIONAL SEMICONDUCTOR PACKAGE CAPABILITIES

Figures 10 and 11 show composite plots of the thermal characteristics of the most common package types in the National Semiconductor Interface Circuits product family. Figure 10 is a composite of the copper lead frame molded package. Figure 11 is a composite of the ceramic (cavity) DIP using poly die attach. These graphs represent board mount still air thermal capabilities. Another, and final, thermal resistance trend will be noticed in these graphs. As the number of device pins increase in a DIP the thermal resistance decreases. Referring back to the thermal flow chart, this trend should, by now, be obvious.

RATINGS ON INTERFACE CIRCUITS DATA SHEETS

In conclusion, all National Semiconductor Interface Products define power dissipation (thermal) capability. This information can be found in the Absolute Maximum Ratings section of the data sheet. The thermal information shown in this application note represents average data for characterization of the indicated package. Actual thermal resistance can vary from ± 10% to ± 15% due to fluctuations in assembly quality, die shape, die thickness, distribution of heat sources on the die, etc. The numbers quoted in the interface data sheets reflect a 15% safety

margin from the average numbers found in this application note. Insuring that total package power remains under a specified level will guarantee that the maximum junction temperature will not exceed the package maximum.

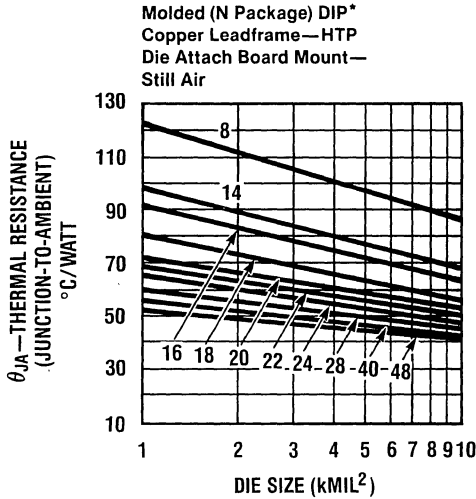
The package power ratings are specified as a maximum power at 25°C ambient with an associated derating factor for ambient temperatures above 25°C. It is easy to determine the power capability at an elevated temperature. The power specified at 25°C should be reduced by the derating factor for every degree of ambient temperature above 25°C. For example, in a given product data sheet the following will be found:

Maximum Power Dissipation* at 25°C	
Cavity Package	1509 mW
Molded Package	1476 mW

*Derate cavity package at 10 mW/°C above 25°C; derate molded package at 11.8 mW/°C above 25°C.

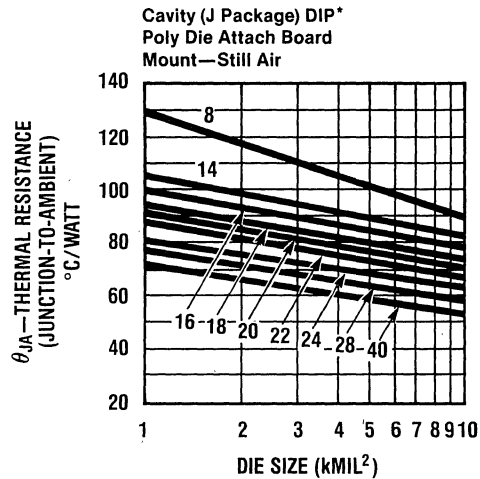
If the molded package is used at a maximum ambient temperature of 70°C, the package power capability is 945 mW.

$$P_D @ 70^\circ\text{C} = 1476 \text{ mW} - (11.8 \text{ mW}/^\circ\text{C}) \times (70^\circ\text{C} - 25^\circ\text{C}) = 945 \text{ mW}$$



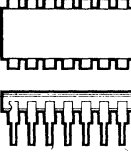
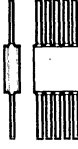

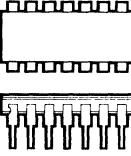
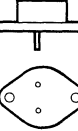
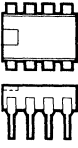
* Packages from 8 to 20-pin 0.3 mil width
 22-pin 0.4 mil width
 24 to 40-pin 0.6 mil width
 TLJ/F15280-10

FIGURE 10. Thermal Resistance vs Die Size vs Package Type (Molded Package)



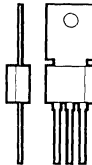
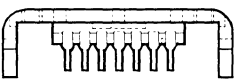
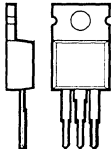
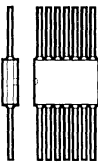

* Packages from 8 to 20-pin 0.3 mil width
 22-pin 0.4 mil width
 24 to 48-pin 0.6 mil width
 TLJ/F15280-11

FIGURE 11. Thermal Resistance vs Die Size vs Package Type (Cavity Package)

	NSC	Signetics	Fairchild	Motorola	TI	RCA	Silicon General	AMD	Raytheon
 <p>14/16 Lead Glass/Metal DIP</p>	D	I	D	L		D	D	D	D, M
 <p>Glass/Metal Flat-Pack</p>	F	Q	F	F	F, S	K	F	F	J, F, Q
 <p>TO-99, TO-100, TO-5</p>	H	T, K, L, DB	H	G	L	S*, V1**	T	H	T, H
 <p>8, 14 and 16-Lead Low-Temperature Ceramic DIP</p>	J	F	R, D	U	J				DC, DD
 <p>TO-3</p>	(Steel) K			KS			K		K
	(Aluminum) KC	DA	K	K	K		K		-LK, TK
 <p>8, 14 and 16-Lead Plastic DIP</p>	N	V, A, B	T, P	P	P, N	E	M, N	PC	N, DN, DP, MP

*With dual-in-line formed leads.

**With radially formed leads.

	NSC	Signetics	Fairchild	Motorola	TI	RCA	Silicon General	AMD	Raytheon
 <p>TO-202 (D-40, Durawatt)</p>	P				KD				
 <p>"SGS" Type Power DIP</p>	S		BP						
 <p>TO-220</p>	T	U	U		KC				
 <p>Low Temperature Glass Hermetic Flat Pack</p>	W		F	F	W		FM		
 <p>TO-92 (Plastic)</p>	Z	S	W	P	LP				

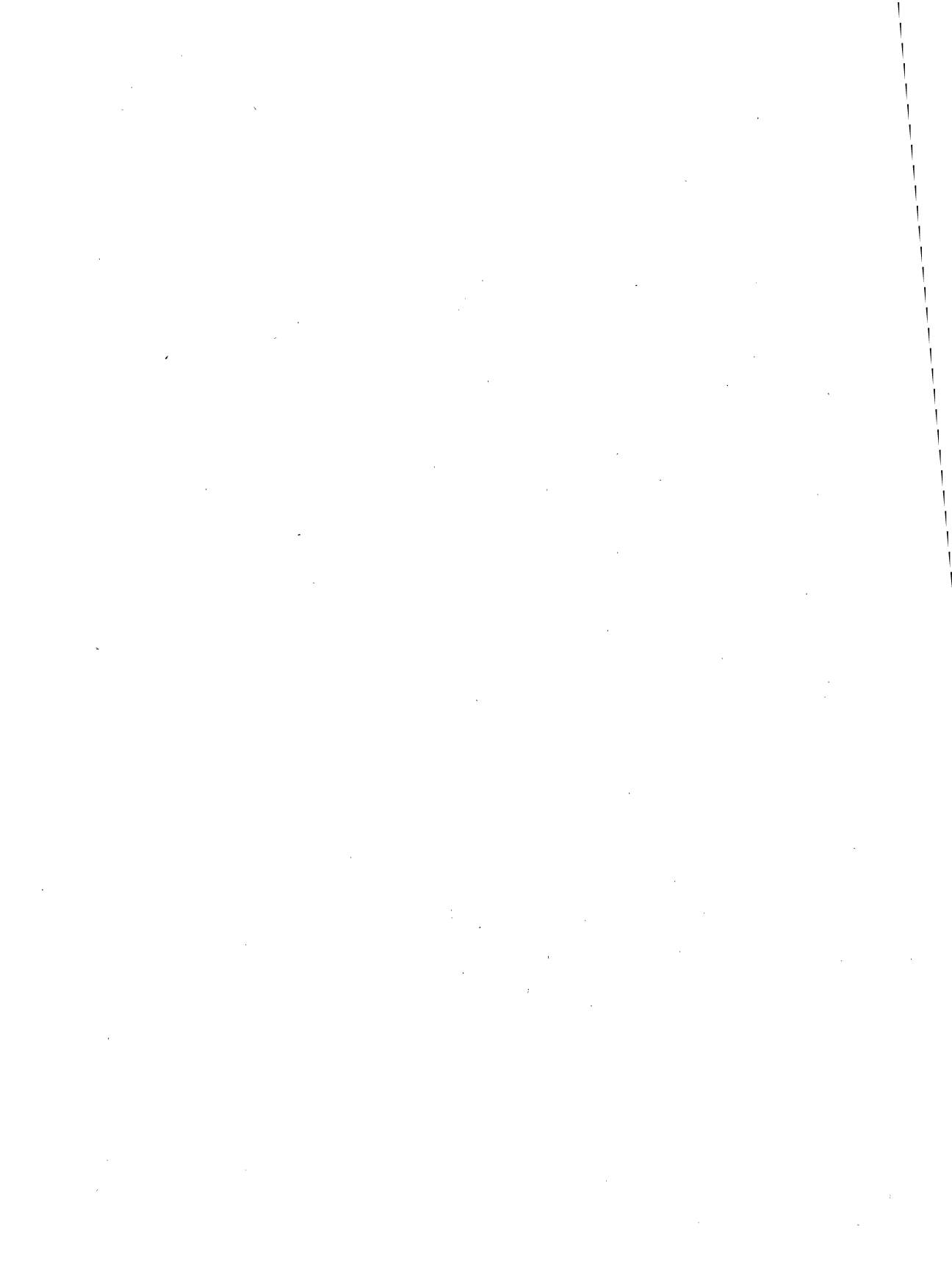
**SECTIONS 13 THROUGH 20 FOR FUTURE
EXPANSION IN SUPPLEMENT BOOKS**



Section 21 Bipolar PROMs

21

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Introduction

GENERAL

This generic Schottky PROM family by National Semiconductor makes available to the industry one of the widest selections in sizes and organizations. Four-bit wide PROMs are provided with 256 to 4096 words in pin compatible 16 and 18 pin dual-in-line packages. The 8-bit wide devices range from 32 to 4096 words in a variety of packages. Being 'generic,' all PROMs share a common programming algorithm.

TITANIUM-TUNGSTEN FUSES

National's new Programmable Read-Only Memories (PROMs) feature titanium-tungsten (Ti:W) fuse links designed to program efficiently with only 10.5 Volts applied. The high performance and reliability of these PROMs are the result of fabrication by a Schottky bipolar process, of which the titanium-tungsten metalization is an integral part, and the use of an on-chip programming circuit.

A major advantage of the titanium-tungsten fuse technology is the low programming voltage of the fuse links. At 10.5 Volts, this virtually eliminates the need for guard-ring devices and wide spacings required for other fuse technologies. Care is taken, however, to minimize voltage drops across the die and to reduce parasitics. The device is designed to ensure that worst-case fuse operating current is low enough for reliable long-term operation. The Darlington programming circuit is liberally designed to insure adequate power density for blowing the fuse links. The complete circuit design is optimized to provide high performance over the entire operating ranges of V_{CC} and temperature.

TESTABILITY

The Schottky PROM die includes extra rows and columns of fusable links for testing the programmability of each chip. These test fuses are placed at the worst-case chip locations to provide the highest possible confidence in the programming tests in the final product. A ROM pattern is also permanently fixed in the additional circuitry and coded to provide a parity check of input address levels. These and other test circuits are used to test for correct operation of the row and column-select circuits and functionality of input and enable gates. All test circuits are available at both wafer and assembled device levels to allow 100% functional and parametric testing at every stage of the test flow.

RELIABILITY

As with all National products, the Ti:W PROMs are subjected to an on-going reliability evaluation by the Reliability Assurance Department. These evaluations employ accelerated life tests, including dynamic high-temperature operating life, temperature-humidity life, temperature cycling, and thermal shock. To date, nearly 7.4 million Schottky Ti:W PROM device hours have been logged, with samples in Epoxy B molded DIP (N-package) and CERDIP (J-package). Device performance in all package configurations is excellent.

Bipolar PROM Selection Guide

Size (Bits)	Organization		DIP (Pins)	Part Number	TAA (Max) in nS	TEA (Max) in nS	ICC (Max) in mA	Temperature Celsius	
256	32 x 8	OC	16	DM54S188	45	30	110	-55 to +125	
	32 x 8	OC	16	DM74S188	35	20	110	0 to +70	
	32 x 8	TS	16	DM54S288	45	30	110	-55 to +125	
	32 x 8	TS	16	DM74S288	35	20	110	0 to +70	
1024	256 x 4	OC	16	DM54S387	60	30	130	-55 to +125	
	256 x 4	OC	16	DM74S387	50	25	130	0 to +70	
	256 x 4	TS	16	DM54S287	60	30	130	-55 to +125	
	256 x 4	TS	16	DM74S287	50	25	130	0 to +70	
2048	512 x 4	OC	16	DM54S570	65	35	130	-55 to +125	
	512 x 4	OC	16	DM74S570	55	30	130	0 to +70	
	512 x 4	TS	16	DM54S571	65	35	130	-55 to +125	
	512 x 4	TS	16	DM74S571	55	30	130	0 to +70	
	512 x 4	OC	16	DM54S570A	60	35	130	-55 to +125	
	512 x 4	OC	16	DM74S570A	45	25	130	0 to +70	
	512 x 4	TS	16	DM54S571A	60	35	130	-55 to +125	
	512 x 4	TS	16	DM74S571A	45	25	130	0 to +70	
	512 x 4	TS	16	DM54S571B	50	35	130	-55 to +125	
	512 x 4	TS	16	DM74S571B	35	25	130	0 to +70	
	256 x 8	TS	20	DM54LS471	70	35	100	-55 to +125	
	256 x 8	TS	20	DM74LS471	60	30	100	0 to +70	
	4096	512 x 8	OC	20	DM54S473	75	35	155	-55 to +125
		512 x 8	OC	20	DM74S473	60	30	155	0 to +70
512 x 8		TS	20	DM54S472	75	35	155	-55 to +125	
512 x 8		TS	20	DM74S472	60	30	155	0 to +70	
512 x 8		OC	20	DM54S473A	60	35	155	-55 to +125	
512 x 8		OC	20	DM74S473A	45	25	155	0 to +70	
512 x 8		TS	20	DM54S472A	60	35	155	-55 to +125	
512 x 8		TS	20	DM74S472A	45	25	155	0 to +70	
512 x 8		TS	20	DM54S472B	50	35	155	-55 to +125	
512 x 8		TS	20	DM74S472B	35	25	155	0 to +70	
512 x 8		OC	24	DM54S475	75	40	170	-55 to +125	
512 x 8		OC	24	DM74S475	65	35	170	0 to +70	
512 x 8		TS	24	DM54S474	75	40	170	-55 to +125	
512 x 8		TS	24	DM74S474	65	35	170	0 to +70	
512 x 8		OC	24	DM54S475A	60	35	170	-55 to +125	
512 x 8		OC	24	DM74S475A	45	25	170	0 to +70	
512 x 8		TS	24	DM54S474A	60	35	170	-55 to +125	
512 x 8		TS	24	DM74S474A	45	25	170	0 to +70	
512 x 8		TS	24	DM54S474B	50	35	170	-55 to +125	
512 x 8		TS	24	DM74S474B	35	25	170	0 to +70	
512 x 8		REG	24*	DM77SR474	40**	30	185	-55 to +125	
512 x 8		REG	24*	DM87SR474	35**	25	185	0 to +70	
512 x 8		REG	24*	DM77SR476	40**	30	185	-55 to +125	
512 x 8		REG	24*	DM77SR25	40**	30	185	-55 to +125	
512 x 8		REG	24*	DM87SR476	35**	25	185	0 to +70	
512 x 8		REG	24*	DM87SR25	35**	25	185	0 to +70	
1024 x 4		OC	18	DM54S572	75	45	140	-55 to +125	
1024 x 4		OC	18	DM74S572	60	35	140	0 to +70	
1024 x 4		TS	18	DM54S573	75	45	140	-55 to +125	
1024 x 4		TS	18	DM74S573	60	35	140	0 to +70	
1024 x 4		OC	18	DM54S572A	60	35	140	-55 to +125	
1024 x 4		OC	18	DM74S572A	45	25	140	0 to +70	
1024 x 4	TS	18	DM54S573A	60	35	140	-55 to +125		
1024 x 4	TS	18	DM74S573A	45	25	140	0 to +70		
1024 x 4	TS	18	DM54S573B	50	35	140	-55 to +125		
1024 x 4	TS	18	DM74S573B	35	25	140	0 to +70		

* - 24 Pin Narrow Dual Inline Package

** - Set up Time

Bipolar PROM Selection Guide

Size (Bits)	Organization	DIP (Pins)	Part Number	TAA (Max) in nS	TEA (Max) in nS	ICC (Max) in mA	Temperature Celsius	
8192	1024 x 8	OC	24	DM77S180	75	35	170	-55 to +125
	1024 x 8	TS	24*	DM77S280	75	35	170	-55 to +125
	1024 x 8	OC	24	DM87S180	55	30	170	0 to +70
	1024 x 8	TS	24*	DM87S280	55	30	170	0 to +70
	1024 x 8	OC	24	DM77S181	75	35	170	-55 to +125
	1024 x 8	TS	24*	DM77S281	75	35	170	-55 to +70
	1024 x 8	OC	24	DM87S181	55	30	170	0 to +70
	1024 x 8	TS	24*	DM87S281	55	30	170	0 to +70
	1024 x 8	TS	24	DM77LS181	175	70	100	-55 to +125
	1024 x 8	TS	24	DM87LS181	120	50	100	0 to +70
	1024 x 8	TS	24	DM77S181A	65	35	170	-55 to +125
	1024 x 8	TS	24	DM87S181A	45	30	170	0 to +70
	1024 x 8	REG.	24*	DM77SR181	50**	30	175	-55 to +125
	1024 x 8	REG.	24*	DM87SR181	40**	25	175	0 to +70
	2048 x 4	OC	18	DM77S184	75	35	140	-55 to +125
	2048 x 4	OC	18	DM87S184	55	30	140	0 to +70
	2048 x 4	TS	18	DM77S185	75	35	140	-55 to +125
	2048 x 4	TS	18	DM87S185	55	30	140	0 to +70
	2048 x 4	TS	18	DM77S185A	60	30	140	-55 to +125
	2048 x 4	TS	18	DM87S185A	45	25	140	0 to +70
2048 x 4	TS	18	DM77S185B	50	30	140	-55 to +125	
2048 x 4	TS	18	DM87S185B	35	25	140	0 to +70	
16384	2048 x 8	OC	24	DM77S190	80	40	175	-55 to +125
	2048 x 8	TS	24*	DM77S290	80	40	175	-55 to +125
	2048 x 8	OC	24	DM87S190	65	30	175	0 to +70
	2048 x 8	TS	24*	DM87S290	65	30	175	0 to +70
	2048 x 8	OC	24	DM77S191	80	40	175	-55 to +125
	2048 x 8	TS	24*	DM77S291	80	40	175	-55 to +125
	2048 x 8	OC	24	DM87S191	65	30	175	0 to +70
	2048 x 8	TS	24*	DM87S291	65	30	175	0 to +70
	2048 x 8	TS	24	DM77S191A	60	35	175	-55 to +125
	2048 x 8	TS	24	DM87S191A	45	30	175	0 to +70
	2048 x 8	TS	24	DM77S191B	50	30	175	-55 to +125
	2048 x 8	TS	24	DM87S191B	35	25	175	0 to +70
	4096 x 4	TS	20	DM77S195A	60	30	170	-55 to +125
	4096 x 4	TS	20	DM87S195A	45	25	170	0 to +70
	4096 x 4	TS	20	DM77S195B	50	30	170	-55 to +125
	4096 x 4	TS	20	DM87S195B	35	25	170	0 to +70
32768	4096 x 8	TS	24	DM77S321	65	35	185	-55 to +125
	4096 x 8	TS	24	DM87S321	55	30	185	0 to +70
	4096 x 8	TS	24*	DM77S421	65	35	185	-55 to +125
	4096 x 8	TS	24*	DM87S421	55	30	185	0 to +70

Absolute Maximum Ratings (Note 1)

Supply Voltage (Note 2)	-0.5 to +7.0V
Input Voltage (Note 2)	-1.2 to +5.5V
Output Voltage (Note 2)	-0.5 to +5.5V
Storage Temperature	-65 to +150C
Lead Temperature (10 seconds)	300C

- * -- 24 Pin Narrow Dual Inline Package
- ** -- Set up Time

Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})			
Military	4.50	5.50	V
Commercial	4.75	5.25	V
Ambient Temperature (T _A)			
Military	-55	+125	°C
Commercial	0	+70	°C
Logical "0" Input Voltage	0	0.8	V
Logical "1" Input Voltage	2.0	5.5	V

Note 1: Absolute maximum ratings are those values beyond which the device may be permanently damaged. They do not mean that the device may be operated at these values.

Note 2: These limits do not apply during programming. For the programming ratings, refer to the programming instructions.

**DM54/74S188, DM54/74S288
(32 X 8) 256-Bit TTL PROMs**
General Description

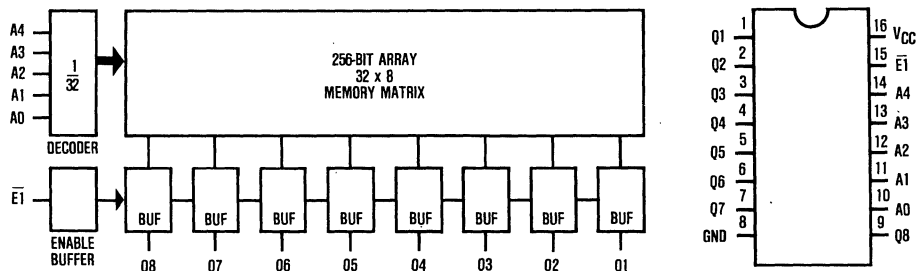
These Schottky memories are organized in the popular 32 words by 8 bits configuration. A memory enable input is provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 8 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
Address access—22ns typ
Enable access—15ns typ
Enable recovery—15ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM74S188		X	X		N,J
DM74S288		X		X	N,J
DM54S188	X		X		J
DM54S288	X			X	J

Block and Connection Diagram


Order Number;
DM74S188 J, DM74S288 J,
DM54S188 J, DM54S288 J
See NS Package J16A

Order Number;
DM74S188 N or DM74S288 N
See NS Package N16A

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM54S188/288			DM74S188/288			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18mA		-0.8	-1.2		-0.8	-1.2	V
C _I	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Inputs Grounded All Outputs Open		70	110		70	110	mA

TRI-STATE® Parameters

I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V Chip Disabled			+50			+50	μA
					-50			-50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0mA	2.4	3.2					V
		I _{OH} = -6.5mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54S188/288			DM74S188/288			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		22	45		22	35	ns
TEA	Enable Access Time	TEVQV		15	30		15	20	ns
TER	Enable Recovery Time	TEXQX		15	35		15	25	ns
TZX	Output Enable Time	TEVQX		15	30		15	20	ns
TXZ	Output Disable Time	TEXQZ		15	35		15	25	ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

**DM54/74S387, DM54/74S287
(256 X 4) 1024-Bit TTL PROMs**

General Description

These Schottky memories are organized in the popular 256 words by 4 bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 4 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

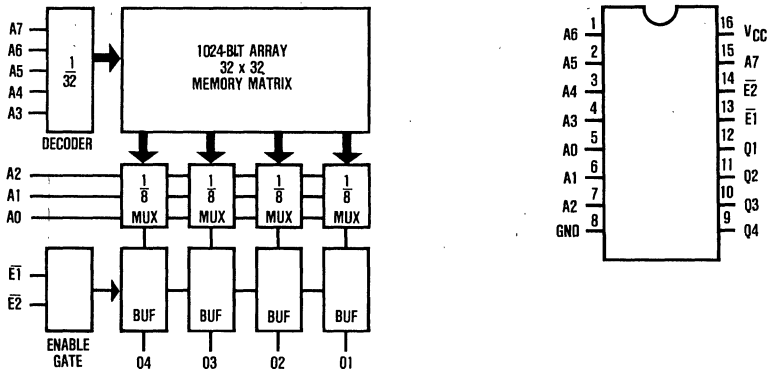
PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
Address access—35ns typ
Enable access—15ns typ
Enable recovery—15ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM74S387		X	X		N,J
DM74S287		X		X	N,J
DM54S387	X		X		J
DM54S287	X			X	J

Block and Connection Diagram



Order Number:
DM74S387 J, DM74S287 J,
DM54S387 J, DM54S287 J
See NS Package J16A

Order Number:
DM74S387 N or DM74S287 N
See NS Package N16A

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM54S387/287			DM74S387/287			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18mA		-0.8	-1.2		-0.8	-1.2	V
C _I	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Inputs Grounded All Outputs Open		80	130		80	130	mA

TRI-STATE® Parameters

I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V Chip Disabled			+50			+50	μA
					-50			-50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0mA	2.4	3.2					V
		I _{OH} = 6.5mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54S387/287			DM74S387/287			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		35	60		35	50	ns
TEA	Enable Access Time	TEVQV		15	30		15	25	ns
TER	Enable Recovery Time	TEXQX		15	30		15	25	ns
TZX	Output Enable Time	TEVQX		15	30		15	25	ns
TXZ	Output Disable Time	TEXQZ		15	30		15	25	ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

**DM54/74S570, DM54/74S571; DM54/74S570A,
DM54/74S571A; DM54/74S571B
(512 x 4) 2048-Bit TTL PROMs**

General Description

These Schottky memories are organized in the popular 512 words by 4 bits configuration. A memory enable input is provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 4 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

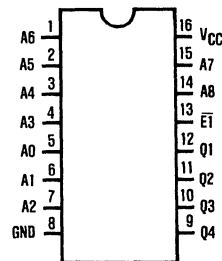
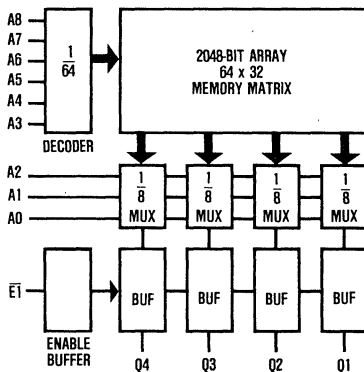
PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
Address access—30ns typ
Enable access—15ns typ
Enable recovery—15ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM74S570		X	X		N,J
DM74S571		X		X	N,J
DM54S570	X		X		J
DM54S571	X			X	J

Block and Connection Diagram



Order Number;
DM74S570 J, DM74S571 J,
DM54S570 J, or DM54S571 J
See NS Package J16A

Order Number;
DM74S570 N or DM74S571 N
See NS Package N16A

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM54S570/571			DM74S570/571			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18mA		-0.8	-1.2		-0.8	-1.2	V
C _I	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Inputs Grounded All Outputs Open		90	130		90	130	mA

TRI-STATE® Parameters

I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V Chip Disabled			+50			+50	μA
					-50			-50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0mA	2.4	3.2					V
		I _{OH} = 6.5mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54S570/571			DM74S570/571			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		40	65		40	55	ns
TEA	Enable Access Time	TEVQV		20	35		20	30	ns
TER	Enable Recovery Time	TEXQX		20	35		20	30	ns
TXZ	Output Enable Time	TEVQX		20	35		20	30	ns
TXZ	Output Disable Time	TEXQZ		20	35		20	30	ns

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol		DM54S571A, B/570A			DM74S571A, B/570A			Units
				Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV	571A/570A	30	60		30	45	ns	
			571B	30	50		30	35	ns	
TEA	Enable Access Time	TEVQV		15	35		15	25	ns	
TER	Enable Recovery Time	TEXQX		15	35		15	25	ns	
TXZ	Output Enable Time	TEVQX		15	35		15	25	ns	
TXZ	Output Disable Time	TEXQZ		15	35		15	25	ns	

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

DM54/74LS471
(256 X 8) 2048-Bit TTL PROMs
General Description

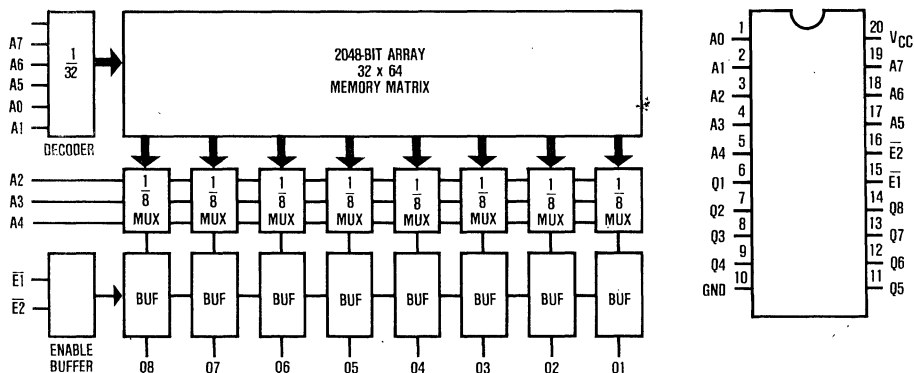
These Schottky memories are organized in the popular 256 words by 8 bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 8 outputs go to the "OFF" or high impedance state.

PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
 - Address access—40ns typ
 - Enable access—15ns typ
 - Enable recovery—15ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM74LS471		X		X	N, J
DM54LS471	X			X	J

Block and Connection Diagram

Order Number:
DM74LS471 J,
DM54LS471 J,
See NS Package J20B

Order Number:
DM74LS471 N
See NS Package N20A

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM54LS471			DM74LS471			Units
			Min	Typ	Max	Min	Typ	Max	
I_{IL}	Input Load Current	$V_{CC} = \text{Max}, V_{IN} = 0.45V$		-80	-250		-80	-250	μA
I_{IH}	Input Leakage Current	$V_{CC} = \text{Max}, V_{IN} = 2.7V$			25			25	μA
		$V_{CC} = \text{Max}, V_{IN} = 5.5V$			1.0			1.0	mA
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}, I_{OL} = 16mA$		0.35	0.50		0.35	0.45	V
V_{IL}	Low Level Input Voltage				0.80			0.80	V
V_{IH}	High Level Input Voltage		2.0			2.0			V
V_C	Input Clamp Voltage	$V_{CC} = \text{Min}, I_{IN} = -18mA$		-0.8	-1.2		-0.8	-1.2	V
C_I	Input Capacitance	$V_{CC} = 5.0, V_{IN} = 2.0V$ $T_A = 25C, 1MHz$		4.0			4.0		pF
C_O	Output Capacitance	$V_{CC} = 5.0V, V_O = 2.0V$ $T_A = 25C, 1MHz, \text{Outputs Off}$		6.0			6.0		pF
I_{CC}	Power Supply Current	$V_{CC} = \text{Max}, \text{Inputs Grounded}$ All Outputs Open		75	100		75	100	mA

TRI-STATE® Parameters

I_{OS}	Short Circuit Output Current	$V_O = 0V, V_{CC} = \text{Max}$ (Note 4)	-20		-70	-20		-70	mA
I_{OZ}	Output Leakage (TRI-STATE)	$V_{CC} = \text{Max}, V_O = 0.45 \text{ to } 2.4V$ Chip Disabled			+50			+50	μA
					-50			-50	μA
V_{OH}	Output Voltage High	$I_{OH} = -2.0mA$	2.4	3.2					V
		$I_{OH} = 6.5mA$				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54LS471			DM74LS471			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		45	70		40	60	ns
TEA	Enable Access Time	TEVQV		15	35		15	30	ns
TER	Enable Recovery Time	TEXQX		15	35		15	30	ns
TZX	Output Enable Time	TEVQX		15	35		15	30	ns
TXZ	Output Disable Time	TEXQZ		15	35		15	30	ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for $V_{CC} = 5.0V$ and $T_A = 25C$.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

DM54/74S473, DM54/74S472, DM54/74S473A,
DM54/74S472A, DM54/74S472B

**DM54/74S473, DM54/74S472; DM54/74S473A,
DM54/74S472A; DM54/74S472B
(512 × 8) 4096-Bit TTL PROMs**

General Description

These Schottky memories are organized in the popular 512 words by 8 bits configuration. A memory enable input is provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 8 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

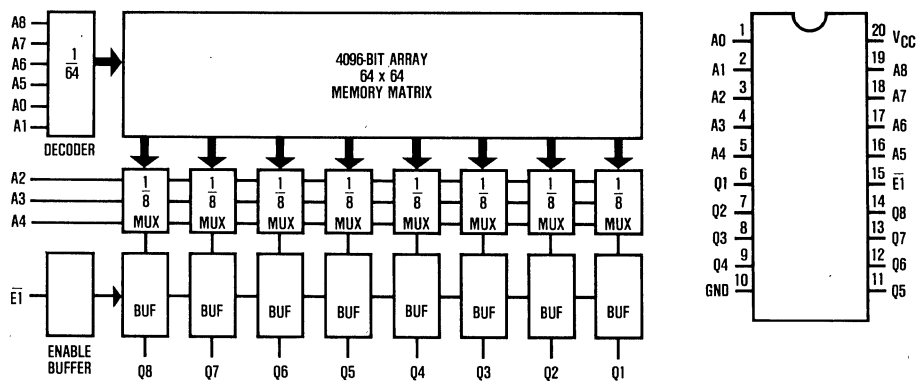
PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
Address access—25ns typ
Enable access—15ns typ
Enable recovery—15ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM74S473		X	X		N,J
DM74S472		X		X	N,J
DM54S473	X		X		J
DM54S472	X			X	J

Block and Connection Diagram



Order Number:
DM74S473 J, DM74S472 J,
DM54S473 J, or DM54S472 J
See NS Package J20B

Order Number:
DM74S473 N or DM74S472 N
See NS Package N20A

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM54S473/472			DM74S473/472			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18mA		-0.8	-1.2		-0.8	-1.2	V
C _i	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Inputs Grounded All Outputs Open		110	155		110	155	mA

TRI-STATE® Parameters

I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V Chip Disabled			+50			+50	μA
					-50			-50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0mA	2.4	3.2					V
		I _{OH} = 6.5mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54S473/472			DM74S473/472			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		40	75		40	60	ns
TEA	Enable Access Time	TEVQV		15	35		15	30	ns
TER	Enable Recovery Time	TEXQX		15	35		15	30	ns
TZX	Output Enable Time	TEVQX		15	35		15	30	ns
TXZ	Output Disable Time	TEXQZ		15	35		15	30	ns

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol		DM54S473A/472A, B			DM74S473A/472A, B			Units
				Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV	473A/472A	25	60		25	45	ns	
			472B	25	50		25	35	ns	
TEA	Enable Access Time	TEVQV	473A/472A	15	35		15	30	ns	
			472B	15	35		15	25	ns	
TER	Enable Recovery Time	TEXQX	473A/472A	15	35		15	30	ns	
			472B	15	35		15	25	ns	
TZX	Output Enable Time	TEVQX	473A/472A	15	35		15	30	ns	
			472B	15	35		15	25	ns	
TXZ	Output Disable Time	TEXQZ	473A/472A	15	35		15	30	ns	
			472B	15	35		15	25	ns	

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

**DM54/74S475, DM54/74S474; DM54/74S475A,
DM54/74S474A; DM54/74S474B**
(512 × 8) 4096-Bit TTL PROMs

General Description

These Schottky memories are organized in the popular 512 words by 8 bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 8 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

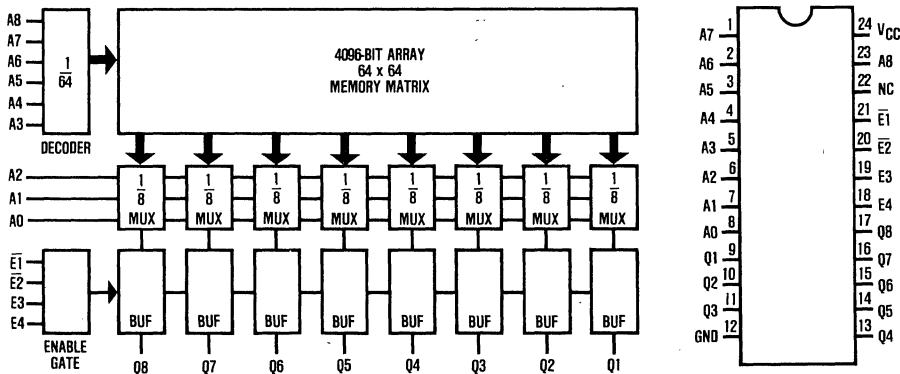
PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
 - Address access—25ns typ
 - Enable access—15ns typ
 - Enable recovery—15ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM74S475		X	X		N,J
DM74S474		X		X	N,J
DM54S475	X		X		J
DM54S474	X			X	J

Block and Connection Diagram



Order Number:
DM74S475 J, DM74S474 J,
DM54S475 J, or DM54S474 J
See NS Package J24A

Order Number:
DM74S475 N or DM74S474 N
See NS Package N24A

DM54/74S475, DM54/74S474, DM54/74S475A,
 DM54/74S474A, DM54/74S474B

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM54S475/474			DM74S475/474			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18mA		-0.8	-1.2		-0.8	-1.2	V
C _I	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Inputs Grounded All Outputs Open		115	170		115	170	mA

TRI-STATE® Parameters

I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V			+50			+50	μA
		Chip Disabled			-50			-50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0mA	2.4	3.2					V
		I _{OH} = 6.5mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54S475/474			DM74S475/474			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		40	75		40	65	ns
TEA	Enable Access Time	TEVQV		20	40		20	35	ns
TER	Enable Recovery Time	TEXQX		20	40		20	35	ns
TZX	Output Enable Time	TEVQX		20	40		20	35	ns
TXZ	Output Disable Time	TEXQZ		20	40		20	35	ns

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54S475A/474A, B			DM74S475A/474A, B			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV 475A/474A 474B		25	60		25	45	ns
				25	50		25	35	ns
TEA	Enable Access Time	TEVQV		15	35		15	25	ns
TER	Enable Recovery Time	TEXQX		15	35		15	25	ns
TZX	Output Enable Time	TEVQX		15	35		15	25	ns
TXZ	Output Disable Time	TEXQZ		15	35		15	25	ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

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DM77/87SR474, DM77/87SR474B (512 × 8) 4k-Bit Registered TTL PROM

General Description

The DM77/87SR474 is an electrically programmable Schottky TTL read-only memory with D-type, master-slave registers on-chip. This device is organized as 512 words by 8-bits and is available in the TRI-STATE[®] output version. Designed to optimize system performance, this device also substantially reduces the cost and size of pipelined microprogrammed systems and other designs wherein accessed PROM data is temporarily stored in a register. The DM77/87SR474 also offers maximal flexibility for memory expansion and data bus control by providing both synchronous and asynchronous output enables. All outputs will go into the "OFF" state if the synchronous chip enable (\overline{CS}) is high before the rising edge of the clock, or if the asynchronous chip enable (\overline{G}) is held high. The outputs are enabled when \overline{CS} is brought low before the rising edge of the clock and \overline{G} is held low. The \overline{CS} flip-flop is designed to power up to the "OFF" state with the application of V_{CC} .

Data is read from the PROM by first applying an address to inputs A0-A8. During the setup time the output of the array is loaded into the master flip-flop of the data register. During the rising edge (low to high transition) of the clock, the data is then transferred to the slave of the flip-flop and will appear on the output if the output is enabled. Following the rising edge clock transition the addresses and synchronous chip enable can be removed and the output data will remain stable.

TRI-STATE[®] is a registered trademark of National Semiconductor Corp.
 TRI-SAFETM is a trademark of National Semiconductor Corp.

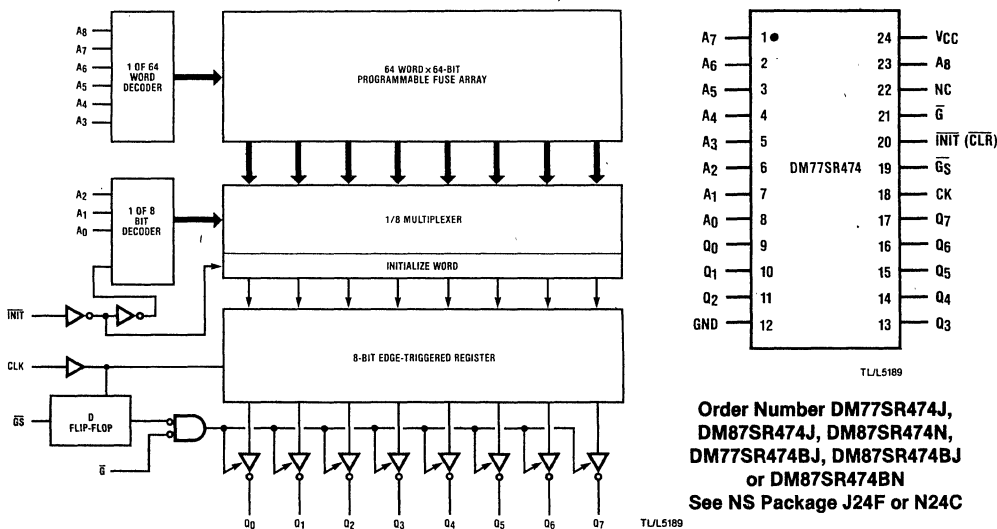
The DM77/87SR474 also features an initialize function, \overline{INIT} . The initialize function provides the user with an extra word of programmable memory which is accessed with single pin control by applying a low on \overline{INIT} . The initialize function is synchronous and is loaded into the output register on the next rising edge of the clock. The unprogrammed state of the \overline{INIT} is all lows, providing a CLEAR function when not programmed.

PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions. Once programmed, it is impossible to go back to a low.

Features

- On-chip, edge-triggered registers
- Synchronous and asynchronous enables for word expansion
- Programmable synchronous register INITIALIZE
- 24-pin, 300 mil thin-dip package
- 35ns address setup and 20ns clock to output for maximum system speed
- Highly reliable, titanium tungsten fuses
- TRI-STATE outputs
- Low voltage TRI-SAFETM programming
- All parameters guaranteed over temperature
- Pinout compatible with DM77SR181 (1k × 8) Registered PROM for future expansion

Block and Connection Diagrams



DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	DM77SR474			DM87SR474			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
I_{IL}	Input Load Current	$V_{CC} = \text{Max.}, V_{IN} = 0.45V$		-80	-250		-80	-250	μA
I_{IH}	Input Leakage Current	$V_{CC} = \text{Max.}, V_{IN} = 2.7V$			25			25	μA
		$V_{CC} = \text{Max.}, V_{IN} = 5.5V$			1.0			1.0	mA
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min.}, I_{OL} = 16mA$		0.35	0.50		0.35	0.45	V
V_{IL}	Low Level Input Voltage				0.80			0.80	V
V_{IH}	High Level Input Voltage		2.0			2.0			V
I_{OZ}	Output Leakage Current	$V_{CC} = \text{Max.}, V_{CEX} = 2.4V$			50			50	μA
V_C	Input Clamp Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18mA$		-0.8	-1.2		-0.8	-1.2	V
C_i	Input Capacitance	$V_{CC} = 5.0V, V_{IN} = 2.0V$ $T_A = 25^\circ C, 1MHz$		4.0			4.0		pF
C_O	Output Capacitance	$V_{CC} = 5.0V, V_O = 2.0V$ $T_A = 25^\circ C, 1MHz, \text{Outputs Off}$		6.0			6.0		pF
I_{CC}	Power Supply Current	$V_{CC} = \text{Max.}, \text{Inputs Grounded}$ All Outputs Open		135	185		135	185	mA

TRI-STATE Parameters

I_{OS}	Short Circuit Output Current	$V_O = 0V, V_{CC} = \text{Max.}$ (Note 4)	-20		-70	-20		-70	mA
I_{OZ}	Output Leakage (TRI-STATE)	$V_{CC} = \text{Max.}, V_O = 0.45 \text{ to } 2.4V$ Chip Disabled	-50		+50	-50		+50	μA
V_{OH}	Output Voltage High	$I_{OH} = -2.0mA$	2.4	3.2					V
		$I_{OH} = -6.5mA$				2.4	3.2		V

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for $V_{CC} = 5.0V$ and $T_A = 25^\circ C$.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

Switching Characteristics

Symbol	Parameter		DM77SR474			DM87SR474			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
$t_{S(A)}$	Address to CLK (High) Setup Time	SR474	55	20		50	20		ns
		SR474B	40	20		35	20		
$t_{H(A)}$	Address to CLK (High) Hold Time		0	-5		0	-5		ns
$t_{S(\overline{INIT})}$	\overline{INIT} to CLK (High) Setup Time		30	20		25	20		ns
$t_{H(\overline{INIT})}$	\overline{INIT} to CLK (High) Hold Time		0	-5		0	-5		ns
$t_{PHL(CLK)}$ $t_{PLH(CLK)}$	Delay from CLK (High) to Output (High or Low)	SR474		15	30		15	27	ns
		SR474B		15	25		15	20	
$t_{WH(CLK)}$ $t_{WL(CLK)}$	CLK Width (High or Low)		25	13		20	13		ns
$t_{S(\overline{GS})}$	\overline{GS} to CLK (High) Setup Time		10	0		10	0		ns
$t_{H(\overline{GS})}$	\overline{GS} to CLK (High) Hold Time		5	0		5	0		ns
$t_{PZL(CLK)}$ $t_{PZH(CLK)}$	Delay from CLK (High) to Output Active (High or Low)			20	35		20	30	ns
$t_{PZL(\overline{G})}$ $t_{PZH(\overline{G})}$	Delay from \overline{G} (Low) to Output Active (High or Low)			15	30		15	25	ns
$t_{PLZ(CLK)}$ $t_{PHZ(CLK)}$	Delay from CLK (High) to Output Inactive (TRI-STATE)			20	35		20	30	ns
$t_{PLZ(\overline{G})}$ $t_{PHZ(\overline{G})}$	Delay from \overline{G} (Low) to Output Inactive (TRI-STATE)			15	30		15	25	ns

DM77187SR476, DM77187SR25, DM77187SR476B, DM77187SR25B (512 × 8) 4k-Bit Registered TTL PROM

General Description

The DM77187SR476 is an electrically programmable Schottky TTL read-only memory with D-type, master-slave registers on-chip. This device is organized as 512 words by 8-bits and is available in the TRI-STATE® output version. Designed to optimize system performance, this device also substantially reduces the cost and size of pipelined microprogrammed systems and other designs wherein accessed PROM data is temporarily stored in a register. The DM77187SR476 also offers maximal flexibility for memory expansion and data bus control by providing both synchronous and asynchronous output enables. All outputs will go into the "OFF" state if the synchronous chip enable (\overline{GS}) is high before the rising edge of the clock, or if the asynchronous chip enable (\overline{G}) is held high. The outputs are enabled when \overline{GS} is brought low before the rising edge of the clock and \overline{G} is held low. The \overline{GS} flip-flop is designed to power up to the "OFF" state with the application of V_{CC} .

Data is read from the PROM by first applying an address to inputs A0-A8. During the setup time the output of the array is loaded into the master flip-flop of the data register. During the rising edge (low to high transition) of the clock, the data is then transferred to the slave of the flip-flop and will appear on the output if the output is enabled. Following the rising edge clock transition the addresses and synchronous chip enable can be removed and the output data will remain stable.

The DM77SR476 also features an initialize function, \overline{INIT} .

TRI-STATE® is a registered trademark of National Semiconductor Corp.
TRI-SAFETM is a trademark of National Semiconductor Corp.

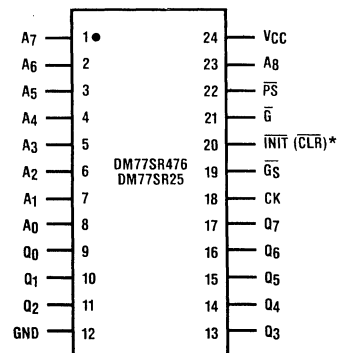
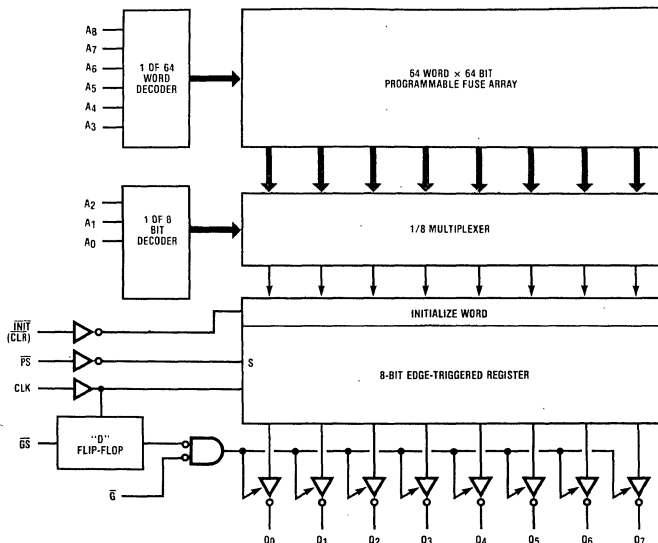
The initialize function provides the user with an extra word of programmable memory which is accessed with single pin control by applying a low on \overline{INIT} . The initialize function is asynchronous and is loaded into the output register when \overline{INIT} is brought low. The unprogrammed state of the \overline{INIT} is all lows, which makes it compatible with the CLEAR function on the AM27S25. \overline{PS} loads ones into the output registers when brought low.

PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions. Once programmed, it is impossible to go back to a low.

Features

- Functionally compatible with AM27S25
- On-chip, edge-triggered registers
- Synchronous and asynchronous enables for word expansion
- Programmable asynchronous INITIALIZE (SR476 only)
- 24-pin, 300 mil thin-dip package
- 35ns address setup and 20ns clock to output for maximum system speed
- Highly reliable, titanium tungsten fuses
- TRI-STATE outputs
- Low voltage TRI-SAFETM programming
- All parameters guaranteed over temperature
- Preset input

Block and Connection Diagrams



* CLR only on DM77187SR25 TUL5190

**Order Number DM77SR476J,
DM77SR25J, DM77187SR476N,
DM77187SR25N, DM77SR476BJ,
DM77SR25BJ, DM77187SR476BN
or DM77187SR25BN**
See NS Package J24F or N24C

DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	DM77SR476, 476B DM77SR25, 25B			DM87SR476, 476B DM87SR25, 25B			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
I_{IL}	Input Load Current	$V_{CC} = \text{Max.}, V_{IN} = 0.45\text{V}$		-80	-250		-80	-250	μA
I_{IH}	Input Leakage Current	$V_{CC} = \text{Max.}, V_{IN} = 2.7\text{V}$			25			25	μA
		$V_{CC} = \text{Max.}, V_{IN} = 5.5\text{V}$			1.0			1.0	mA
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min.}, I_{OL} = 16\text{mA}$		0.35	0.50		0.35	0.45	V
V_{IL}	Low Level Input Voltage				0.80			0.80	V
V_{IH}	High Level Input Voltage		2.0			2.0			V
I_{OZ}	Output Leakage Current	$V_{CC} = \text{Max.}, V_{CEX} = 2.4\text{V}$			50			50	μA
V_C	Input Clamp Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18\text{mA}$		-0.8	-1.2		-0.8	-1.2	V
C_I	Input Capacitance	$V_{CC} = 5.0\text{V}, V_{IN} = 2.0\text{V}$ $T_A = 25^\circ\text{C}, 1\text{MHz}$		4.0			4.0		pF
C_O	Output Capacitance	$V_{CC} = 5.0\text{V}, V_O = 2.0\text{V}$ $T_A = 25^\circ\text{C}, 1\text{MHz}, \text{Outputs Off}$		6.0			6.0		pF
I_{CC}	Power Supply Current	$V_{CC} = \text{Max.}, \text{Inputs Grounded}$ All Outputs Open		135	185		135	185	mA

TRI-STATE Parameters

I_{OS}	Short Circuit Output Current	$V_O = 0\text{V}, V_{CC} = \text{Max.}$ (Note 4)	-20		-70	-20		-70	mA
I_{OZ}	Output Leakage (TRI-STATE)	$V_{CC} = \text{Max.}, V_O = 0.45 \text{ to } 2.4\text{V}$ Chip Disabled	-50		+50	-50		+50	μA
V_{OH}	Output Voltage High	$I_{OH} = -2.0\text{mA}$	2.4	3.2					V
		$I_{OH} = -6.5\text{mA}$				2.4	3.2		V

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for $V_{CC} = 5.0\text{V}$ and $T_A = 25^\circ\text{C}$.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

Switching Characteristics

Symbol	Parameter		DM77SR476, 476B DM77SR25, 25B			DM87SR476, 476B DM87SR25, 25B			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
$t_{S(A)}$	Address to CLK (High) Setup Time	SR476, SR25	55	20		50	20		ns
		SR476B, SR25B	40	20		35	20		
$t_{H(A)}$	Address to CLK (High) Hold Time		0	-5		0	-5		ns
$t_{PHL(CLK)}$ $t_{PLH(CLK)}$	Delay from CLK (High) to Output (High or Low)	SR476, SR25		15	30		15	27	ns
		SR476B, SR25B		15	25		15	20	
$t_{WH(CLK)}$ $t_{WL(CLK)}$	CLK Width (High or Low)		25	13		25	13		ns
$t_{S(\overline{GS})}$	\overline{GS} to CLK (High) Setup Time		10	0		10	0		ns
$t_{H(\overline{GS})}$	\overline{GS} to CLK (High) Hold Time		5	0		5	0		ns
$t_{PLH(\overline{PS})}$	Delay from \overline{PS} (Low) to Output (High)			20	30		20	25	ns
$t_{PLH(\overline{INIT})}$ $t_{PHL(\overline{INIT})}$	Delay from \overline{INIT} (Low) to Output (Low or High)			20	30		20	25	ns
$t_{WL(\overline{PS})}$	\overline{PS} Pulse Width (Low)		15	10		15	10		ns
$t_{WL(\overline{INIT})}$	\overline{INIT} Pulse Width (Low)		15	10		15	10		ns
$t_{S(\overline{PS})}$	\overline{PS} Recovery (High) to CLK (High)		25	10		20	10		ns
$t_{S(\overline{INIT})}$	\overline{INIT} Recovery (High) to CLK (High)		25	10		20	10		ns
$t_{PZL(CLK)}$ $t_{PZH(CLK)}$	Delay from CLK (High) to Active Output (High or Low)			20	35		20	30	ns
$t_{PZL(\overline{G})}$ $t_{PZH(\overline{G})}$	Delay from \overline{G} (Low) to Active Output (Low or High)			15	30		15	25	ns
$t_{PLZ(CLK)}$ $t_{PHZ(CLK)}$	Delay from CLK (High) to Inactive Output (TRI-STATE)			20	35		20	30	ns
$t_{PLZ(\overline{G})}$ $t_{PHZ(\overline{G})}$	Delay from \overline{G} (High) to Inactive Output (TRI-STATE)			15	30		15	25	ns

**DM54/74S572, DM54/74S573; DM54/74S572A,
DM54/74S573A; DM54/74S573B
(1024 × 4) 4096-Bit TTL PROMs**

General Description

These Schottky memories are organized in the popular 1024 words by 4 bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 4 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

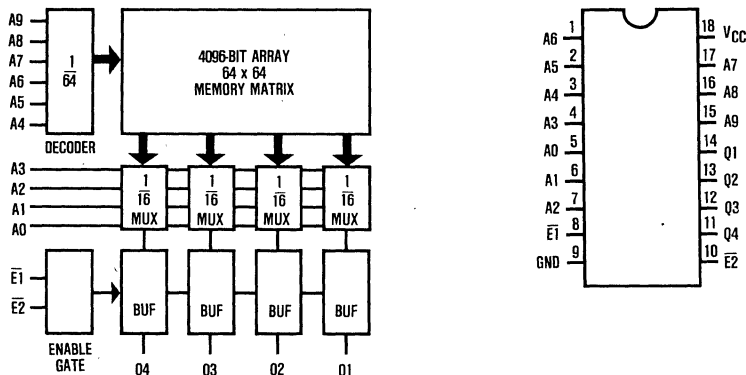
PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
Address access—25ns typ
Enable access—15ns typ
Enable recovery—15ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM74S572		X	X		N,J
DM74S573		X		X	N,J
DM54S572	X		X		J
DM54S573	X			X	J

Block and Connection Diagram



Order Number:
DM74S572 J, DM74S573 J,
DM54S572 J, or DM54S573 J
See NS Package J18A

Order Number:
DM74S572 N or DM74S573 N
See NS Package N18A

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM54S572/573			DM74S572/573			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{JN} = -18mA		-0.8	-1.2		-0.8	-1.2	V
C _I	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Inputs Grounded All Outputs Open		100	140		100	140	mA

TRI-STATE® Parameters

I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V Chip Disabled			+50			+50	μA
					-50			-50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0mA	2.4	3.2					V
		I _{OH} = 6.5mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54S572/573			DM74S572/573			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		40	75		40	60	ns
TEA	Enable Access Time	TEVQV		20	45		20	35	ns
TER	Enable Recovery Time	TEXQX		20	45		20	35	ns
TZX	Output Enable Time	TEVQX		20	45		20	35	ns
TXZ	Output Disable Time	TEXQZ		20	45		20	35	ns

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM54S572A/573A, B			DM74S572A/573A, B			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV	572A/573A	25	60		25	45	ns
			573B		25	50		25	35
TEA	Enable Access Time	TEVQV		15	35		15	25	ns
TER	Enable Recovery Time	TEXQX		15	35		15	25	ns
TZX	Output Enable Time	TEVQX		15	35		15	25	ns
TXZ	Output Disable Time	TEXQZ		15	35		15	25	ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result

DM77/87S180, DM77/87S181, DM77/87S181A, DM77/87S280, DM77/87S281, DM77/87S281A

**DM77/87S180/DM77/87S181; DM77/87S181A;
DM77/87S280/DM77/87S281; DM77/87S281A
(1024 × 8) 8192-Bit TTL PROMs**

General Description

These Schottky memories are organized in the popular 1024 words by 8 bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 8 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

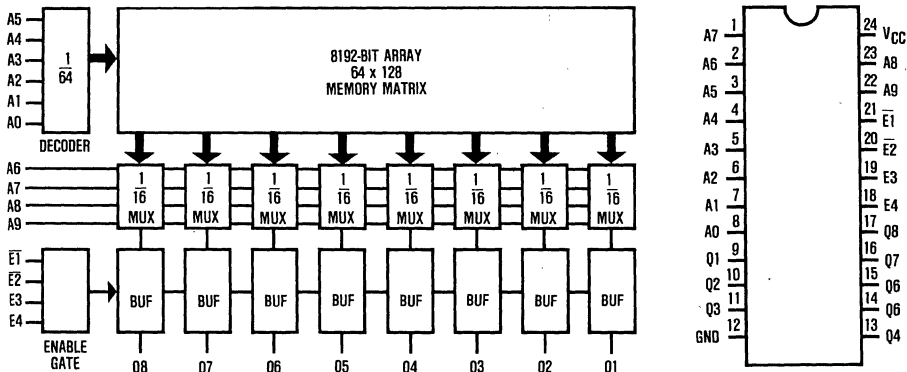
PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
Address access—35ns typ
Enable access—15ns typ
Enable recovery—15ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package	24-Pin Standard	24-Pin Narrow-Dip
DM87S180		X	X		N,J	X	
DM87S181		X		X	N,J	X	
DM77S180	X		X		J	X	
DM77S181	X			X	J	X	
DM87S280		X	X		N,J		X
DM87S281		X		X	N,J		X
DM77S280	X		X		J		X
DM77S281	X			X	J		X

Block and Connection Diagram



Order Number:
DM87S180 J, DM87S181 J,
DM77S180 J, DM77S181 J
See NS Package J24A

Order Number:
DM87S280 J, DM87S281 J,
DM77S280 J, DM77S281 J
See NS Package J24C

Order Number:
DM87S180 N or DM87S181 N
See NS Package N24A

Order Number:
DM87S280 N, or DM87S281 N
See NS Package N24C

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM77S180/181 DM77S280/281			DM87S180/181 DM87S280/281			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18mA		-0.8	-1.2		-0.8	-1.2	V
C _I	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Inputs Grounded All Outputs Open		115	170		115	170	mA

TRI-STATE® Parameters

I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V Chip Disabled			+50			+50	μA
					-50			-50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0mA	2.4	3.2					V
		I _{OH} = 6.5mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM77S180/181 DM77S280/281			DM87S180/181 DM87S280/281			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		40	75		40	55	ns
TEA	Enable Access Time	TEVQV		15	35		15	30	ns
TER	Enable Recovery Time	TEXQV		15	35		15	30	ns
TZX	Output Enable Time	TEVQX		15	35		15	30	ns
TXZ	Output Disable Time	TEXQZ		15	35		15	30	ns

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM77S181A			DM87S181A			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV		35	65		35	45	ns
TEA	Enable Access Time	TEVQV		15	35		15	30	ns
TER	Enable Recovery Time	TEXQX		15	35		15	30	ns
TZX	Output Enable Time	TEVQX		15	35		15	30	ns
TXZ	Output Disable Time	TEXQZ		15	35		15	30	ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

**DM77/87LS181
(1024 X 8) 8192-Bit TTL PROMs**

General Description

These Schottky memories are organized in the popular 1024 words by 8 bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 8 outputs go to the "OFF" or high impedance state. The memories are available in TRI-STATE® versions.

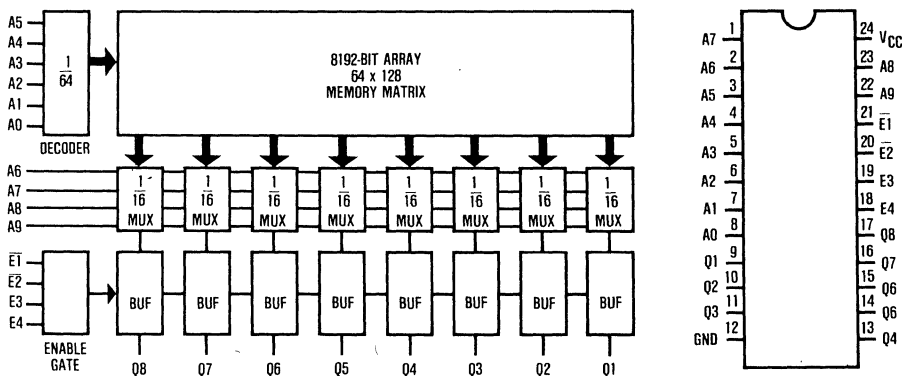
PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
Address access—100ns typ
Enable access—35ns typ
Enable recovery—35ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM87LS181		X		X	N,J
DM77LS181	X			X	J

Block and Connection Diagram



Order Number:
DM87LS181-J,
or DM77LS181-J
See NS Package J24A

Order Number:
DM87LS181-N
See NS Package N24A

DC Electrical Characteristics (Note 3)

Sym	Parameter	Conditions	DM77LS181			DM87LS181			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V			-150			-100	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 5.5V			40			50	μA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 8mA			0.50			0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18mA			-1.2			-1.2	V
C _I	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Inputs Grounded All Outputs Open			100			100	mA

TRI-STATE® Parameters

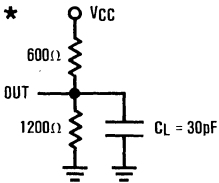
I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-10		-70	-10		-85	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.5 to 5.5V Chip Disabled			+50 -50			+40 -40	μA μA
V _{OH}	Output Voltage High	I _{OH} = -1.0mA I _{OH} = 1.6mA	2.4	3.2		2.4	3.2		V V

AC Electrical Characteristics (With Specified Load* and Operating Conditions)

Sym	Parameter	JEDEC Symbol	DM77LS181			DM87LS181			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	Address Access Time	TAVQV			120			100	ns
TEA	Enable Access Time	TEVQV			70			50	ns
TER	Enable Recovery Time	TEXQX			70			50	ns
TZX	Output Enable Time	TEVQZ			70			50	ns
TXZ	Output Disable Time	TEXQZ			70			50	ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.



DM77/87SR181 (1024 × 8) 8k-Bit Registered TTL PROM

General Description

The DM77/87SR181 is an electrically programmable Schottky TTL read-only memory with D-type, master-slave registers on chip. This device is organized as 1024-words by 8-bits and is available in the tri-state output version. Designed to optimize system performance, this device also substantially reduces the cost and size of pipelined microprogrammed systems and other designs wherein accessed PROM data is temporarily stored in a register. The DM77/87SR181 also offers maximal flexibility for memory expansion and data bus control by providing both synchronous and asynchronous output enables. All outputs will go into the "OFF" state if the synchronous chip enable (\overline{CS}) is high before the rising edge of the clock, or if the asynchronous chip enable (\overline{C}) is held high. The outputs are enabled when \overline{CS} is brought low before the rising edge of the clock and \overline{C} is held low. The \overline{CS} flip-flop is designed to power up to the "OFF" state with the application of V_{CC} .

Data is read from the PROM by first applying an address to inputs A0-A9. During the setup time the output of the array is loaded into the master flip-flop of the data register. During the rising edge (low to high transition) of the clock, the data is then transferred to the slave of the flip-flop and will appear on the output if the output is enabled. Following the rising edge clock transition the addresses and synchronous chip enable can be removed and the output data will remain stable.

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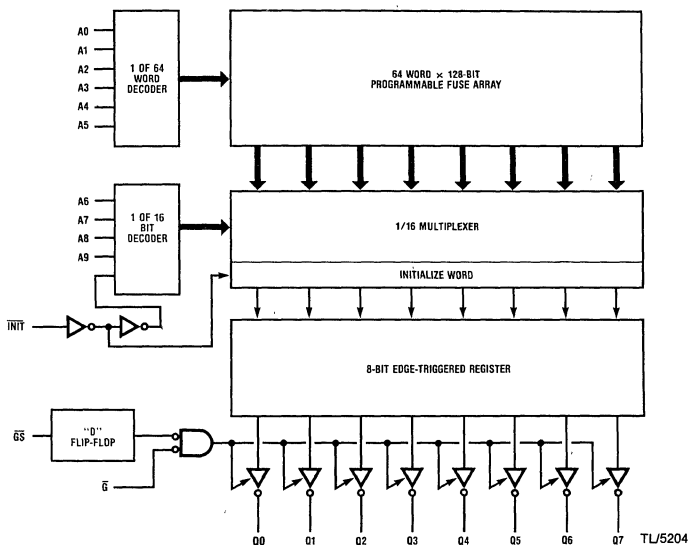
The DM77SR181 also features an initialize function \overline{INIT} . The initialize function provides the user with an extra word of programmable memory which is accessed with single pin control by applying a low on \overline{INIT} . The initialize function is synchronous and is loaded into the output register on the next rising edge of the clock. The unprogrammed state of the \overline{INIT} is all lows.

PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions. Once programmed, it is impossible to go back to a low.

Features

- On-chip, edge-triggered registers
- Synchronous and asynchronous enables for word expansion
- Programmable register INITIALIZE
- 24-pin, 300 mil package
- 40ns address setup and 20ns clock to output for maximum system speed
- Highly reliable, titanium tungsten fuses
- TRI-STATE® outputs
- Low voltage TRI-SAFETM programming
- All parameters guaranteed over temperature

Block Diagram



DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	DM77SR181			DM87SR181			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
I_{IL}	Input Load Current	$V_{CC} = \text{Max.}, V_{IN} = 0.45\text{V}$		-80	-250		-80	-250	μA
I_{IH}	Input Leakage Current	$V_{CC} = \text{Max.}, V_{IN} = 2.7\text{V}$			25			25	μA
		$V_{CC} = \text{Max.}, V_{IN} = 5.5\text{V}$			1.0			1.0	mA
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min.}, I_{OL} = 16\text{mA}$		0.35	0.50		0.35	0.45	V
V_{IL}	Low Level Input Voltage				0.80			0.80	V
V_{IH}	High Level Input Voltage		2.0			2.0			V
I_{OZ}	Output Leakage Current	$V_{CC} = \text{Max.}, V_{CEX} = 2.4\text{V}$			50			50	μA
V_C	Input Clamp Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18\text{mA}$		-0.8	-1.2		-0.8	-1.2	V
C_I	Input Capacitance	$V_{CC} = 5.0\text{V}, V_{IN} = 2.0\text{V}$ $T_A = 25^\circ\text{C}, 1\text{MHz}$		4.0			4.0		pF
C_O	Output Capacitance	$V_{CC} = 5.0\text{V}, V_O = 2.0\text{V}$ $T_A = 25^\circ\text{C}, 1\text{MHz}, \text{Outputs Off}$		6.0			6.0		pF
I_{CC}	Power Supply Current	$V_{CC} = \text{Max.}, \text{Inputs Grounded}$ All Outputs Open		115	175		115	175	mA

TRI-STATE Parameters

I_{OS}	Short Circuit Output Current	$V_O = 0\text{V}, V_{CC} = \text{Max.}$ (Note 4)	-20		-70	-20		-70	mA
I_{OZ}	Output Leakage (TRI-STATE)	$V_{CC} = \text{Max.}, V_O = 0.45 \text{ to } 2.4\text{V}$ Chip Disabled	-50		+50	-50		+50	μA
V_{OH}	Output Voltage High	$I_{OH} = -2.0\text{mA}$	2.4	3.2					V
		$I_{OH} = -6.5\text{mA}$				2.4	3.2		V

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for $V_{CC} = 5.0\text{V}$ and $T_A = 25^\circ\text{C}$.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

Switching Characteristics

Symbol	Parameter	Conditions	DM77SR181			DM87SR181			Units	
			Min.	Typ.	Max.	Min.	Typ.	Max.		
$t_{S(A)}$	Address to CLK (High) Setup Time	$C_L = 30\text{pF}$	50	20		40	20		ns	
$t_{H(A)}$	Address to CLK (High) Hold Time		0	-5		0	-5		ns	
$t_{S(INIT)}$	INIT to CLK (High) Setup Time		35	20		30	20		ns	
$t_{H(INIT)}$	INIT to CLK (High) Hold Time		0	-5		0	-5		ns	
$t_{PHL(CLK)}$	Delay from CLK (High) to Output (High or Low)			15	30		15	20	ns	
$t_{WH(CLK)}$ $t_{WL(CLK)}$	CLK Width (High or Low)		25	13		20	13		ns	
$t_{S(GS)}$	\overline{GS} to CLK (High) Setup Time		15	0		15	0		ns	
$t_{H(GS)}$	\overline{GS} to CLK (High) Hold Time		5	0		5	0		ns	
$t_{PZL(CLK)}$ $t_{PZH(CLK)}$	Delay from CLK (High) to Active Output (High or Low)	$C_L = 30\text{pF}$		20	30		20	25	ns	
$t_{PZL(G)}$ $t_{PZH(G)}$	Delay from \overline{G} (Low) to Active Output (High or Low)				15	30		15	25	ns
$t_{PZL(CLK)}$ $t_{PHZ(CLK)}$	Delay from CLK (High) to Inactive Output (TRI-STATE)		$C_L = 5\text{pF}$ (Note 1)		20	30		20	25	ns
$t_{PZL(G)}$ $t_{PHZ(G)}$	Delay from \overline{G} (High) to Inactive Output (TRI-STATE)					15	30		15	25

Note: All typical values are for $V_{CC} = 5\text{V}$, $T_A = 25^\circ\text{C}$.



DM77/87S184, DM77/87S185, DM77/87S185A, DM77/87S185B (2048 × 4) 8192-Bit TTL PROMs

General Description

These Schottky memories are organized in the popular 2048 words by 4 bits configuration. A memory enable input is provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 4 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

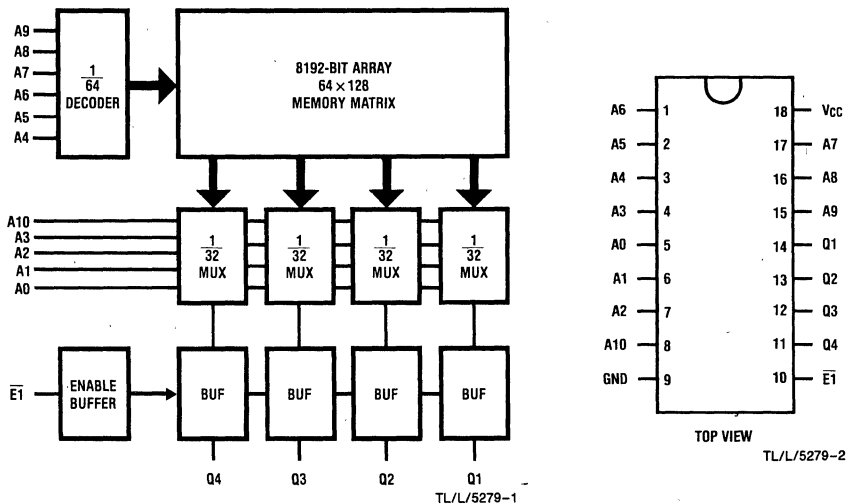
Features

- Advanced titanium-tungsten (Ti-W) fuses
- Schottky-clamped for high speed
 - Address access—35 ns max (B Version)
 - Enable access—15 ns typ
 - Enable recovery—15 ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

	Military	Commercial	Open-Collector	TRI-STATE	Package
DM87S184		X	X		N,J
DM87S185		X		X	N,J
DM77S184	X		X		J
DM77S185	X			X	J

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Block and Connection Diagram



DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	DM77S184/185			DM87S184/185			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16 mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18 mA	-0.8	-1.2		-0.8	-1.2		V
C _I	Input Capacitance	V _{CC} = 5.0, V _{IN} = 2.0V T _A = 25C, 1 MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25C, 1 MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Input Grounded All Outputs Open		100	140		100	140	mA

TRI-STATE Parameters

I _{OS}	Short Circuit Output Current :	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V Chip Disabled	-50		+50	-50		+50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0 mA	2.4	3.2					V
		I _{OH} = -6.5 mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Symbol	JEDEC Symbol	Parameters	DM77S184/185			DM87S184/185			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	TAVQV	Address Access Time		40	70		40	55	ns
TEA	TEVQV	Enable Access Time		15	30		15	25	ns
TER	TEXQX	Enable Recovery Time		15	30		15	25	ns
TZX	TEVQX	Output Enable Time		15	30		15	25	ns
TXZ	TEXQZ	Output Disable Time		15	30		15	25	ns

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Symbol	JEDEC Symbol	Parameters	DM77S185A/B			DM87S185A/B			Units
			Min	Typ	Max	Min	Typ	Max	
TAA	TAVQV	Address Access Time		30	60		30	45	ns
	185B			25	50		25	35	ns
TEA	TEVQV	Enable Access Time		15	30		15	25	ns
TER	TEXQX	Enable Recovery Time		15	30		15	25	ns
TZX	TEVQX	Output Enable Time		15	30		15	25	ns
TXZ	TEXQZ	Output Disable Time		15	30		15	25	ns

Note 3: These limits apply over the entire operating range unless otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.



**DM77/87S190, DM77/87S191; DM77/87S290,
DM77/87S291; DM77/87S190A, DM77/87S191A;
DM77/87S290A, DM77/87S291A; DM77/87S190B,
DM77/87S191B; DM77/87S290B, DM77/87S291B
(2048 × 8) 16,384-Bit TTL PROMs**

General Description

These Schottky memories are organized in the popular 2048 words by 8 bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 8 outputs go to the "OFF" or high impedance state. The memories are available in both open-collector and TRI-STATE® versions.

PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

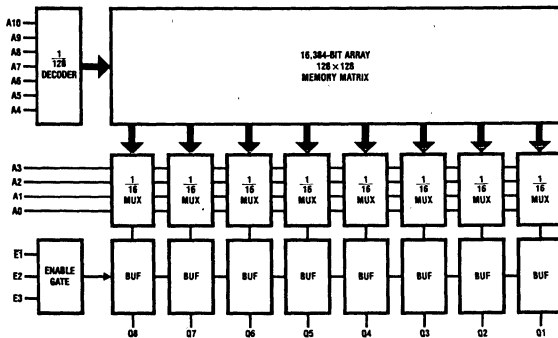
Features

- Advanced tungsten (W) fuses
- Schottky-clamped for high speed
 - Address access—35 ns max (B version)
 - Enable access—15 ns typ
 - Enable recovery—15 ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming

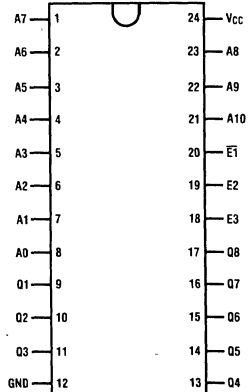
	Military	Commercial	Open-Collector	TRI-STATE	Package	24-Pin Standard	24-Pin Thin-Dip
DM87S190		X	X		N,J	X	
DM87S191		X		X	N,J	X	
DM77S190	X		X		J	X	
DM77S191	X			X	J	X	
DM87S290		X	X		N,J		X
DM87S291		X		X	N,J		X
DM77S290	X		X		J		X
DM77S291	X			X	J		X

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Block and Connection Diagrams



TL/L/5278-1



TOP VIEW
TL/L/5278-2

AC Electrical Characteristics (With Standard Load and Operating Conditions)

JEDEC Symbol	Sym	Parameter	DM77S190/191 DM77S290/291			DM87S190/191 DM87S290/291			Units
			Min	Typ	Max	Min	Typ	Max	
TAVQV	191A	t _{AA} Address Access Time		35	60		35	45	ns
	191B			30	30		30	35	ns
TEVQV	t _{EA}	Enable Access Time		15	35		15	30	ns
TEXQX	t _{ER}	Enable Recovery Time		15	35		15	30	ns
TEVQX	t _{ZX}	Output Enable Time		15	35		15	30	ns
TEXQZ	t _{XZ}	Output Disable Time		15	35		15	30	ns

DC Electrical Characteristics (Note 3)

Symbols	Parameter	Condition	DM77S190/191 DM77S290/291			DM87S190/191 DM87S290/291			Units
			Min	Typ	Max	Min	Typ	Max	
I _{IL}	Input Load Current	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
		V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16 mA		0.35	0.50		0.35	0.45	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
I _{OZ}	Output Leakage Current (Open-Collector Only)	V _{CC} = Max, V _{CEX} = 2.4V			50			50	μA
		V _{CC} = Max, V _{CEX} = 5.5V			100			100	μA
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18 mA		-0.8	-1.2		-0.8	-1.2	V
C _I	Input Capacitance	V _{CC} = 5.0V, V _{IN} = 2.0V T _A = 25°C, 1 MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5.0V, V _O = 2.0V T _A = 25°C, 1 MHz, Outputs Off		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, Input Grounded All Outputs Open		120	175		120	175	mA

TRI-STATE Parameters

I _{OS}	Short Circuit Output Current	V _O = 0V, V _{CC} = Max (Note 4)	-20		-70	-20		-70	mA
I _{OZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45V to 2.4V Chip Disabled	-50		50	-50		50	μA
V _{OH}	Output Voltage High	I _{OH} = -2.0 mA	2.4	3.2					V
		I _{OH} = -6.5 mA				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

JEDEC Symbol	Sym	Parameter	DM77S191A/B DM77S291A/B			DM87S191A/B DM87S291A/B			Units
			Min	Typ	Max	Min	Typ	Max	
TAVQV	191A/291A	t _{AA} Address Access Time		30	60		30	45	ns
	191B/291B			30	50		30	35	ns
TEVQV	t _{EA}	Enable Access Time		15	35		15	25	ns
TEXQX	t _{ER}	Enable Recovery Time		15	35		15	25	ns
TEVQX	t _{ZX}	Output Enable Time		15	35		15	25	ns
TEXQZ	t _{XZ}	Output Disable Time		15	35		15	25	ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5.0V and T_A = 25°C.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

DM77S195A/DM87S195A, DM77S195B/DM87S195B (4096 x 4) 16,384-Bit TTL PROM

General Description

These Schottky memories are organized in the popular 4096 words by 4 bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the 4 outputs go to the OFF or high impedance state. The memories are available in TRI-STATE[®] version only.

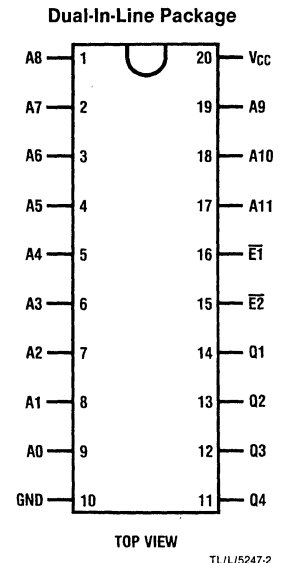
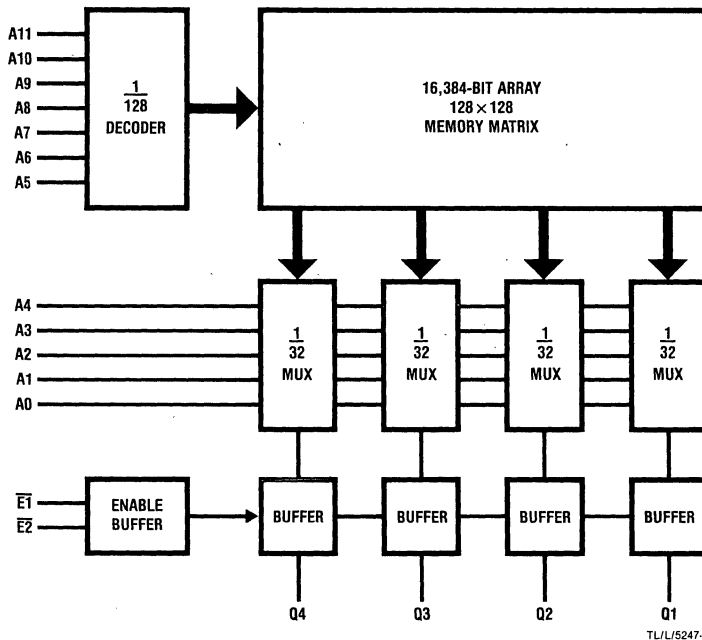
PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

Features

- Advanced tungsten (W) fuse technology
- Schottky-clamped for high speed
 - Address access—30 ns typ
 - Enable access—15 ns typ
 - Enable recovery—15 ns typ
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE[™] programming

	Military	Commercial	TRI-STATE	Package
DM87S195A/B		X	X	N,J
DM77S195A/B	X		X	J

Block and Connection Diagrams



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DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	DM77S195A/B			DM87S195A/B			Units
			Min	Typ	Max	Min	Typ	Max	
I_{IL}	Input Load Current	$V_{CC} = \text{Max}, V_{IN} = 0.45V$		- 80	- 250		- 80	- 250	μA
I_{IH}	Input Leakage Current	$V_{CC} = \text{Max}, V_{IN} = 2.7V$			25			25	μA
		$V_{CC} = \text{Max}, V_{IN} = 5.5V$			1.0			1.0	mA
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}, I_{OL} = 16 \text{ mA}$		0.35	0.50		0.35	0.45	V
V_{IL}	Low Level Input Voltage				0.80			0.80	V
V_{IH}	High Level Input Voltage		2.0			2.0			V
V_C	Input Clamp Voltage	$V_{CC} = \text{Min}, I_{IN} = - 18 \text{ mA}$		- 0.8	- 1.2		- 0.8	- 1.2	V
C_I	Input Capacitance	$V_{CC} = 5.0V, V_{IN} = 2.0V$ $T_A = 25^\circ C, 1 \text{ MHz}$		4.0			4.0		pF
C_O	Output Capacitance	$V_{CC} = 5.0V, V_O = 2.0V$ $T_A = 25^\circ C, 1 \text{ MHz}, \text{Outputs Off}$		6.0			6.0		pF
I_{CC}	Power Supply Current	$V_{CC} = \text{Max}, \text{Inputs Grounded}$ All Outputs Open			170			170	mA

TRI-STATE PARAMETERS

I_{OS}	Short Circuit Output Current	$V_O = 0V, V_{CC} = \text{Max}$ (Note 4)	- 20		- 70	- 20		- 70	mA
I_{OZ}	Output Leakage (TRI-STATE)	$V_{CC} = \text{Max}, V_O = 0.45V \text{ to } 2.4V$			+ 50			+ 50	μA
		Chip Disabled			- 50			- 50	μA
V_{OH}	Output Voltage High	$I_{OH} = - 2.0 \text{ mA}$	2.4	3.2					V
		$I_{OH} = 6.5 \text{ mA}$				2.4	3.2		V

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for $V_{CC} = 5.0V$ and $T_A = 25^\circ C$.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

AC Electrical Characteristics (with standard load and operating conditions)

Symbol		Parameter	DM77S195A/195B			DM87S195A/195B			Units	
Alternate	JEDEC Standard		Min	Typ	Max	Min	Typ	Max		
t_{AA}	TAVQV	Address Access Time	195A		30	60		30	45	ns
			195B		30	50		25	35	ns
t_{EA}	TEVQV	Enable Access Time		15	30		15	25	ns	
t_{ER}	TEXQX	Enable Recovery Time		15	30		15	25	ns	
t_{ZX}	TEVQX	Output Enable Time		15	30		15	25	ns	
t_{XZ}	TEXQZ	Output Disable Time		15	30		15	25	ns	

**DM77/87S321, DM77/87S421; DM77/87S321A, DM77/87S421A
(4096 x 8) 32,768-Bit TTL PROMs**

General Description

These Schottky memories are organized in the popular 4,096 words by 8-bits configuration. Memory enable inputs are provided to control the output states. When the device is enabled, the outputs represent the contents of the selected word. When disabled, the eight outputs go to the "OFF" or high impedance state.

PROMs are shipped from the factory with lows in all locations. A high may be programmed into any selected location by following the programming instructions.

The DM77/87S321 and DM77/87S421 program the same as all other nonregistered PROMs from National.

Features

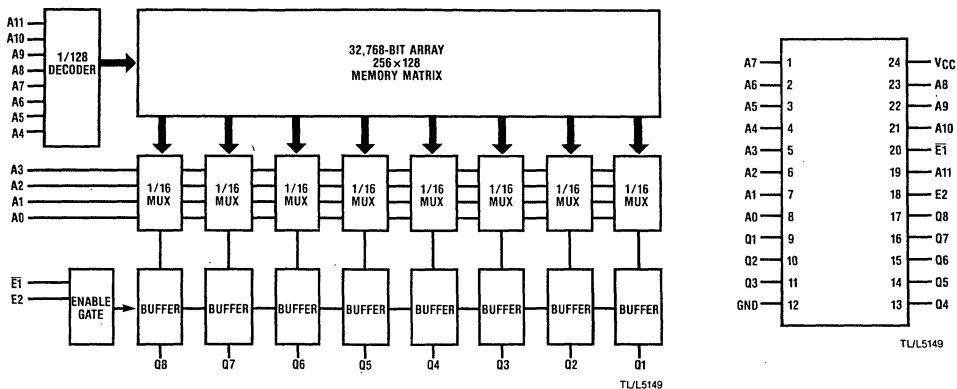
- Advanced fuse technology
- Schottky-clamped for high speed
 - Address access—35 ns typ.
 - Enable access—20ns typ.
 - Enable recovery—20ns typ.
- PNP inputs for reduced input loading
- All DC and AC parameters guaranteed over temperature
- Low voltage TRI-SAFE™ programming
- Generic programming.

	Military	Commercial	TRI-STATE®	Package
DM87S321, A		X	X	N,J
DM77S321, A	X		X	J
DM87S421, A		X	X	N,J*
DM77S421, A	X		X	J*

TRI-STATE® is a registered trademark of National Semiconductor Corp.
TRI-SAFETM is a trademark of National Semiconductor Corp.

*Thin-Dip (0.3") package

Block and Connection Diagrams



DC Electrical Characteristics (Note 3)

Symbol	Parameter	Conditions	DM77S321/421			DM87S321/421			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
I_{IL}	Input Load Current	$V_{CC} = \text{Max.}, V_{IN} = 0.45\text{V}$		-80	-250		-80	-250	μA
I_{IH}	Input Leakage Current	$V_{CC} = \text{Max.}, V_{IN} = 2.7\text{V}$			25			25	μA
		$V_{CC} = \text{Max.}, V_{IN} = 5.5\text{V}$			1.0			1.0	mA
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min.}, I_{OL} = 12\text{mA}$		0.35	0.50		0.35	0.45	V
V_{IL}	Low Level Input Voltage				0.80			0.80	V
V_{IH}	High Level Input Voltage		2.0			2.0			V
V_C	Input Clamp Voltage	$V_{CC} = \text{Min.}, I_{IN} = -18\text{mA}$		-0.8	-1.2		-0.8	-1.2	V
C_I	Input Capacitance	$V_{CC} = 5.0, V_{IN} = 2.0\text{V}$ $T_A = 25^\circ\text{C}, 1\text{MHz}$		4.0			4.0		pF
C_O	Output Capacitance	$V_{CC} = 5.0\text{V}, V_O = 2.0\text{V}$ $T_A = 25^\circ\text{C}, 1\text{MHz}, \text{Outputs Off}$		6.0			6.0		pF
I_{CC}	Power Supply Current	$V_{CC} = \text{Max.},$ All Outputs Open		135	185		135	185	mA

TRI-STATE Parameters

I_{OS}	Short Circuit Output Current	$V_O = 0\text{V}, V_{CC} = \text{Max.}$ (Note 4)	-20		-70	-20		-70	mA
I_{OZ}	Output Leakage (TRI-STATE)	$V_{CC} = \text{Max.}, V_O = 0.45 \text{ to } 2.4\text{V}$ Chip Disabled	-50		+50	-50		+50	μA
V_{OH}	Output Voltage High	$I_{OH} = -2.0\text{mA}$	2.4	3.2					V
		$I_{OH} = -6.5\text{mA}$				2.4	3.2		V

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Symbol	Parameter	JEDEC Symbol	DM77S321/421			DM87S321/421			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
T_{AA}	Address Access Time	TAVQV		40	65		40	55	ns
T_{EA}	Enable Access Time	TEVQV		20	35		20	30	ns
T_{ER}	Enable Recovery Time	TEXQX		20	35		20	30	ns
T_{ZX}	Output Enable Time	TEVQX		20	35		20	30	ns
T_{XZ}	Output Disable Time	TEXQZ		20	35		20	30	ns

AC Electrical Characteristics (With Standard Load and Operating Conditions)

Symbol	Parameter	JEDEC Symbol	DM77S321A/421A			DM87S321A/421A			Units
			Min.	Typ.	Max.	Min.	Typ.	Max.	
T_{AA}	Address Access Time	TAVQV		35			35		ns
T_{EA}	Enable Access Time	TEVQV		20			20		ns
T_{ER}	Enable Recovery Time	TEXQX		20			20		ns
T_{ZX}	Output Enable Time	TEVQX		20			20		ns
T_{XZ}	Output Disable Time	TEXQZ		20			20		ns

Note 3: These limits apply over the entire operating range unless stated otherwise. All typical values are for $V_{CC} = 5.0\text{V}$ and $T_A = 25^\circ\text{C}$.

Note 4: During I_{OS} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

Non-Registered PROM Programming Procedure

National Schottky PROMs are shipped from the factory with all fuses intact. As a result, the outputs will be low (logical "0") for all addresses. To generate high (logical "1") levels at the outputs, the device must be programmed. Information regarding commercially available programming equipment may be obtained from National. If it is desired to build your own programmer, the following conditions must be observed:

1. Programming should be attempted only at ambient temperatures between 15 and 30 degrees Celsius.
2. Address and enable inputs must be driven with TTL logic levels during programming and verification.
3. Programming will occur at the selected address when V_{CC} is at 10.5 volts, and at the selected bit location when the output pin, representing that bit, is at 10.5 volts, and the device is subsequently enabled. To achieve these conditions in the appropriate sequence, the following procedure must be followed:
 - a) Select the desired word by applying high or low levels to the appropriate address inputs. Disable the device by applying a high level to one or more "active low" chip enable inputs.
 - b) Increase V_{CC} from nominal to 10.5 volts (plus or minus 0.5V) with a slew rate between 1.0 and 10.0V/ μ s. Since V_{CC} is the source of the current required to program the fuse as well as the I_{CC} for the device at the programming voltage, it must be capable of supplying 750mA at 11.0 volts.
 - c) Select the output where a logical high is desired by raising that output voltage to 10.5 volts (plus or minus 0.5V). Limit the slew rate from 1.0 to 10.0V/ μ s. This voltage change may occur simultaneously with the increase in V_{CC} , but must not precede it. It is critical that only one output at a time be programmed since the internal circuits can only supply programming current to one bit at a time. Outputs not being programmed must be left open or connected to a high impedance source of 20k Ω minimum (Remember that the outputs of the device are disabled at this time).
 - d) Enable the device by taking the chip enable(s) to a low level. This is done with a pulse of 10 μ s. The 10 μ s duration refers to the time that the circuit (device) is enabled. Normal input levels are used and rise and fall times are not critical.
 - e) Verify that the bit has been programmed by first removing the programming voltage from the output and then reducing V_{CC} to 4.0 volts (plus or minus 0.2V). Verification at a V_{CC} level of 4.0 volts will guarantee proper output states over the V_{CC} and temperature range of the programmed part. The device must be enabled to sense the state of the outputs. During verification, the loading of the output must be within specified I_{OL} and I_{OH} limits. Steps b, c, and d must be repeated up to 10 times or until verification that the bit has been programmed.
 - f) Following verification, apply five additional programming pulses to the bit being programmed. The programming procedure is now complete for the selected bit.
 - g) Repeat steps a through f for each bit to be programmed to a high level. If the procedure is performed on an automatic programmer, the duty cycle of V_{CC} at the programming voltage must be limited to a maximum of 25%. This is necessary to minimize device junction temperatures. After all selected bits are programmed, the entire contents of the memory should be verified.

Note: Since only an enabled device is programmed, it is possible to program these parts at the board level if all programming parameters are complied with.

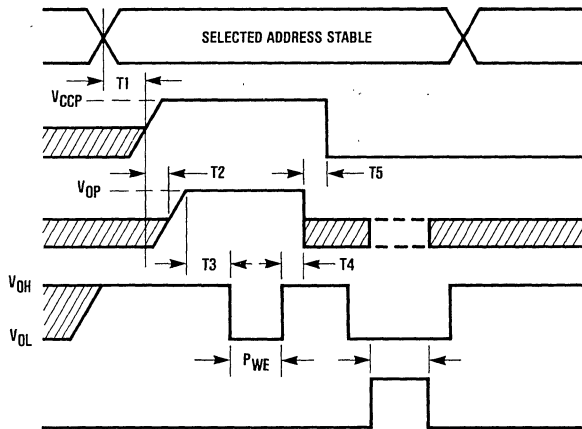
Programming Parameters Do not test or you may program the device

Sym	Parameters	Conditions	Min	Recommended Value	Max	Units
V _{CCP}	Required V _{CC} for Programming		10.0	10.5	11.0	V
I _{CCP}	I _{CC} During Programming	V _{CC} = 11V			750	mA
V _{OP}	Required Output Voltage for Programming		10.0	10.5	11.0	V
I _{OP}	Output Current while Programming	V _{OUT} = 11V			20	mA
I _{RR}	Rate of Voltage Change of V _{CC} or Output		1.0		10.0	V/μs
P _{WE}	Programming Pulse Width (Enabled)		9	10	11	μs
V _{CCV}	Required V _{CC} for Verification		3.8	4.0	4.2	V
M _{DC}	Maximum Duty Cycle for V _{CC} at V _{CCP}			25	25	%

Programming Waveforms Non-Registered PROM

T1 = 100ns min.
 T2 = 5μs min. T2 may be > 0 if V_{CCP} rises at the same rate or faster than (V_{OP})
 T3 = 100ns min.
 T4 = 100ns min.
 T5 = 100ns min.

P_{WE} is repeated for 5 additional pulses after verification of V_{OH} indicates a bit has been programmed.



Registered PROM Programming Procedure

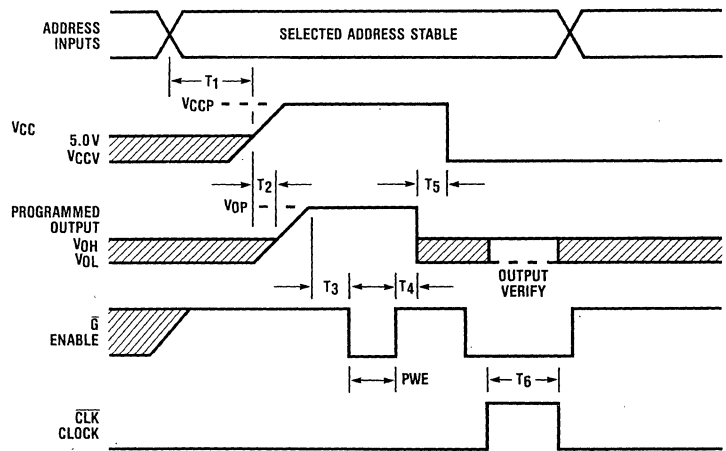
National Schottky PROMs are shipped from the factory with all fuses intact. As a result, the outputs will be low (logical '0') for all addresses. To generate high (logical '1') levels at the outputs, the device must be programmed. Information regarding commercially available programming equipment may be obtained from National. If it is desired to build your own programmer, the following conditions must be observed.

1. Programming should be attempted only at ambient temperatures between 15°C and 30°C.
2. Address and Enable inputs must be driven with TTL logic levels during programming and verification.
3. Programming will occur at the selected address when V_{CC} is at 10.5V, and at the selected bit location when the output pin, representing that bit, is at 10.5V, and the device is subsequently enabled. To achieve these conditions in the appropriate sequence, the following procedure must be followed:
 - a) Select the desired word by applying high or low levels to the appropriate address inputs. Disable the device by applying a high level to asynchronous chip Enable input \overline{G} . \overline{GS} is held low during the entire programming time.
 - b) Increase V_{CC} from nominal to 10.5V ($\pm 0.5V$) with a slew rate between 1.0 and 10V/ μs . Since V_{CC} is the source of the current required to program the fuse as well as the I_{CC} for the device at the programming voltage, it must be capable of supplying 750mA at 11V.
 - c) Select the output where a logical high is desired by raising that output voltage to 10.5V ($\pm 0.5V$). Limit the slew rate from 1.0 to 10V/ μs . This voltage change may occur simultaneously with the increase in V_{CC} , but must not precede it. It is critical that only one output at a time be programmed since the internal circuits can only supply programming current to one bit at a time. Outputs not being programmed must be left open or connected to a high impedance source of 20k Ω minimum. (Remember that the outputs of the device are disabled at this time.)
 - d) Enable the device by taking the chip enable (\overline{G}) to a low level. This is done with a pulse of 10 μs . The 10 μs duration refers to the time that the circuit (device) is enabled. Normal input levels are used and rise and fall times are not critical.
 - e) Verify that the bit has been programmed by first removing the programming voltage from the output and then reducing V_{CC} to 4.0V ($\pm 0.2V$). Verification at a V_{CC} level of 4.0V will guarantee proper output states over the V_{CC} and temperature range of the programmed part. Each data verification must be preceded by a positive going (low to high) clock edge to load the data from the array into the output register. The device must be enabled to sense the state of the outputs. During verification, the loading of the output must be within specified I_{OL} and I_{OH} limits. Steps b, c, and d must be repeated up to 10 times or until verification that the bit has been programmed.
 - f) The initialize word is programmed by setting \overline{INIT} input to a logic low and programming the initialize word output by output in the same manner as any other address. This can be accomplished by inverting the A9 address input from the PROM programmer and applying it to the \overline{INIT} input. Using this method, the initialize word will program at address 512.
 - g) Following verification, apply five additional programming pulses to the bit being programmed. The programming procedure is now complete for the selected bit.
 - h) Repeat steps a through f for each bit to be programmed to a high level. If the procedure is performed on an automatic programmer, the duty cycle of V_{CC} at the programming voltage must be limited to a maximum of 25%. This is necessary to minimize device junction temperatures. After all selected bits are programmed, the entire contents of the memory should be verified.

Programming Parameters Do not test or you may program the device

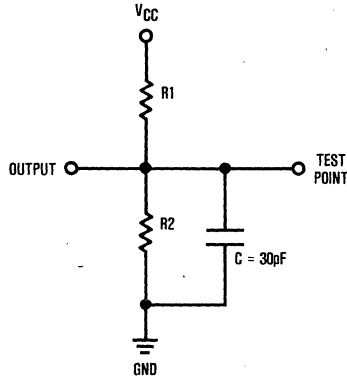
Sym	Parameters	Conditions	Min	Recommended Value	Max	Units
V _{CCP}	Required V _{CC} for Programming		10.0	10.5	11.0	V
I _{CCP}	I _{CC} During Programming	V _{CC} = 11V			750	mA
V _{OP}	Required Output Voltage for Programming		10.0	10.5	11.0	V
I _{OP}	Output Current while Programming	V _{OUT} = 11V			20	mA
I _{RR}	Rate of Voltage Change of V _{CC} or Output		1.0		10.0	V/μs
P _{WE}	Programming Pulse Width (Enabled)		9	10	11	μs
V _{CCV}	Required V _{CC} for Verification		3.8	4.0	4.2	V
M _{DC}	Maximum Duty Cycle for V _{CC} at V _{CCP}			25	25	%

Programming Waveforms Registered PROM



- T₁ = 100 ns MIN.
- T₂ = 5 μs MIN. (T₂ MAY BE > 0 IF V_{CCP} RISES AT THE SAME RATE OR FASTER THAN V_{OP}.)
- T₃ = 100 ns MIN.
- T₄ = 100 ns MIN.
- T₅ = 100 ns MIN.
- T₆ = 50 ns MIN.

Standard Test Load



* Device input waveform characteristics are:
 Repetition rate = 1MHz
 Source impedance = 50Ω
 Rise and Fall times = 2.5ns max.
 (1.0 to 2.0 volt levels)

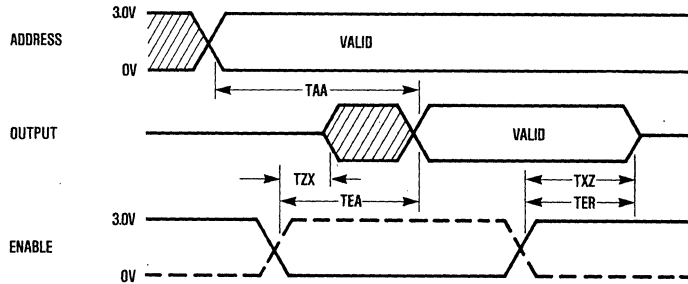
* TAA is measured with stable enable inputs.

* TEA and TER are measured from the 1.5 volt level on inputs and outputs with all address and enable inputs stable at applicable levels.

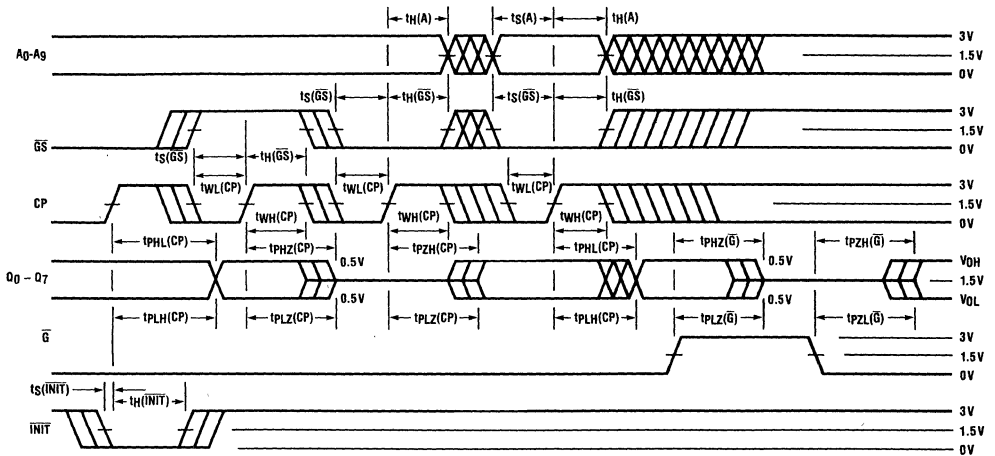
* For $I_{OL} = 16mA$, $R1 = 300\Omega$ and $R2 = 600\Omega$
 for $I_{OL} = 12mA$, $R1 = 400\Omega$ and $R2 = 800\Omega$.

* "C" includes scope and jig capacitance.

Switching Time Waveforms Non-Registered PROM



Switching Waveforms Registered PROM



Key To Timing Diagram

WAVEFORM	INPUTS	OUTPUTS	WAVEFORM	INPUTS	OUTPUTS
	MUST BE STEADY	WILL BE STEADY		DON'T CARE: ANY CHANGE PERMITTED	CHANGING: STATE UNKNOWN
	MAY CHANGE FROM H TO L	WILL BE CHANGING FROM H TO L		DOES NOT APPLY	CENTER LINE IS HIGH IMPEDANCE "OFF" STATE
	MAY CHANGE FROM L TO H	WILL BE CHANGING FROM L TO H			

Approved Programmers for NSC PROMs

MANUFACTURER	SYSTEM #
DATA I/O	5/17/19/29A
PRO-LOG	M910, M980
KONTRON	MPP80S
STAG	PPX
AIM	RP400
DIGELEC	UP803
STARPLEX™	

Quality Enhancement Programs For Bipolar Memory

A+ PROGRAM*			B+ PROGRAM		
Test	Condition	Guaranteed LOT AQL 5	Test	Condition	Guaranteed LOT AQL 5
D.C. Parametric And Functionality	25°C	0.05	D.C. Parametric And Functionality	25°C	0.05
	Each Temperature Extreme	0.05		Each Temperature Extreme	0.05
A.C. Parametric	25°C	0.4	A.C. Parametric	25°C	0.4
Mechanical	Critical	0.01	Mechanical	Critical	0.01
	Major	0.28		Major	0.28
Seal Tests Hermetic	Fine Leak (5 x 10 ⁻⁸)	0.4	Seal Tests Hermetic	Fine Leak (5 x 10 ⁻⁸)	0.4
	Gross	0.4		Gross	0.4

*Includes 160 hours of burn-in at 125°C.

DM76S64/DM86S64 Bipolar Character Generator

General Description

The DM76S64/DM86S64 is a 64-character bipolar character generator with serial output designed primarily for the CRT display marketplace, and packaged in a standard 16-pin DIP. The DM76S64/DM86S64 incorporates several CRT system level functions, as well as a 7 x 9 or 5 x 7 row scan character font. The DM76S64/DM86S64 performs the system functions of parallel to serial shifting, character address latching, character spacing and character line spacing. These system functions have required extra packages in the past.

Shifted characters can be generated by the on-chip subtractor.

The clear input and the load enable input are active low. Load enable is synchronous with the dot clock. Both the line clock and the dot clock are positive edge-triggered. When the address latch control signal is high,

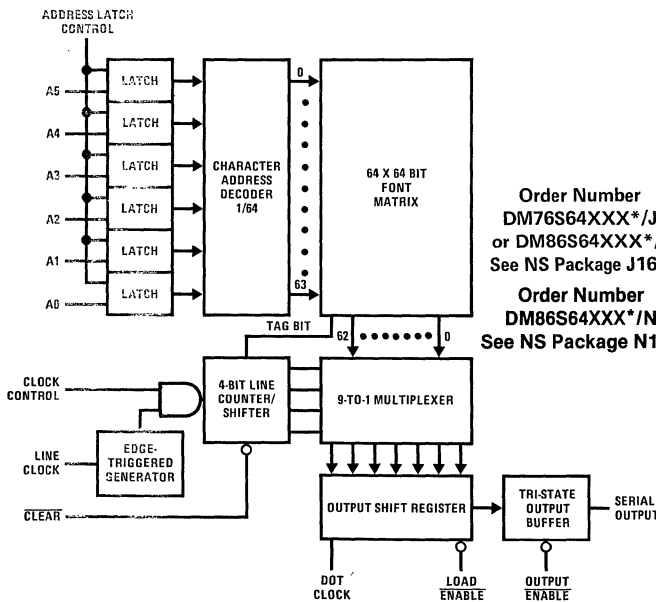
the character addresses "fall through" the latch. And when the address latch control signal goes low, the character addresses are latched.

Features

- 64-character—row scan
- 5 x 7 or 7 x 9 font
- Custom fonts available with shift options
- Serial output
- 16-pin package
- 35 MHz typ clock rate
- On-chip input latches
- On-chip shift register
- On-chip dot blanking
- On-chip row blanking
- TRI-STATE® output

	7 x 9	5 x 7	FONT	PACKAGE
DM76S64BWF/DM86S64BWF	X		Upper Case Block Letters	N, J
DM76S64CAE/DM86S64CAE	X		Shifted Lower Case Block	N, J
DM76S64CAB/DM86S64CAB		X	Upper Case Block Letters	N, J
DM76S64CAH/DM86S64CAH		X	Shifted Lower Case Block	N, J
DM76S64CTA/DM86S64CTA	X		ASCII Character Set	N, J
DM76S64CTB/DM86S64CTB	X		ASCII Numerals and Control	N, J

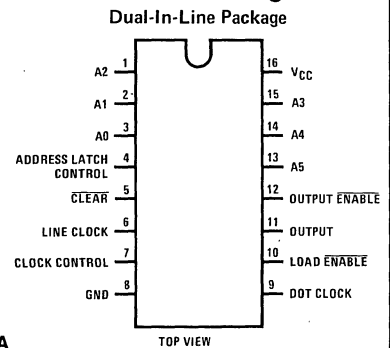
Block Diagram



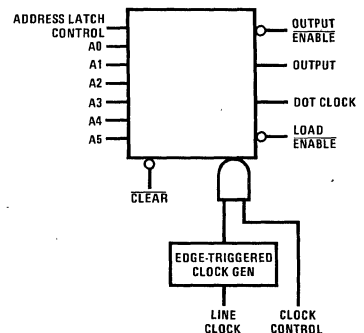
Order Number
DM76S64XXX*/J
or DM86S64XXX*/J
See NS Package J16A

Order Number
DM86S64XXX*/N
See NS Package N16A

Connection Diagram



Logic Symbol



* alpha pattern designators

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Absolute Maximum Ratings (Note 1)

Supply Voltage	-0.5V to +7V
Input Voltage	-1.5V to +5.5V
Output Voltage	-0.5V to +5.5V
Storage Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})			
DM76S64	4.5	5.5	V
DM86S64	4.75	5.25	V
Ambient Temperature (T_A)			
DM76S64	-55	+125	°C
DM86S64	0	+70	°C
Logical "0" Voltage	0	0.6	V
Logical "1" Voltage	2.0	5.5	V

DC Electrical Characteristics (Note 2)

SYM	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
I_{IL}	Input Load Current	$V_{CC} = \text{Max}, V_{IN} = 0.45V$			-800	μA
I_{IH}	Input Leakage Current	$V_{CC} = \text{Max}, V_{IN} = 2.4V$			40	μA
I_I	Input Leakage Current	$V_{CC} = \text{Max}, V_{IN} = 5.5V$			1	mA
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}, I_{OL} = 16 \text{ mA}$		0.35	0.45	V
V_{IL}	Low Level Input Voltage	$V_{CC} = \text{Min}$			0.80	V
V_{IH}	High Level Input Voltage	$V_{CC} = \text{Min}$	2.0			V
V_C	Input Clamp Voltage	$V_{CC} = \text{Min}, I_{IN} = -12 \text{ mA}$		-0.8	-1.5	V
C_{IN}	Input Capacitance	$V_{CC} = 5V, V_{IN} = 2V, T_A = 25^\circ C,$ 1 MHz		4.0		pF
C_O	Output Capacitance	$V_{CC} = 5V, V_O = 2V, T_A = 25^\circ C,$ 1 MHz, Output "OFF"		6.0		pF
I_{CC}	Power Supply Current	$V_{CC} = \text{Max}, \text{All Inputs Grounded},$ Output Open		80	140	mA

TRI-STATE PARAMETERS

I_{SC}	Output Short-Circuit Current	$V_O = 0V, V_{CC} = \text{Max}$	-15		-70	mA
I_{HZ}	Output Leakage	$V_{CC} = \text{Max}, V_O = 0.45 \text{ to } 2.4V,$ Chip Disabled			± 40	μA
V_{OH}	Output Voltage High	$I_{OH} = -2 \text{ mA}$	2.4	3.2		V

AC Electrical Characteristics (Note 2)

SYM	PARAMETER	CONDITIONS	DM76S64			DM86S64			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
T_{DO}	Access Time								
	Dot Clock to Output			25	50		25	40	ns
	Output Enable			10	35		10	30	ns
T_{ER}	Output Disable			13	35		13	30	ns
	Set-Up Time								
T_{S1}	Load to Dot Clock		25	7		20	7		ns
T_{S2}	Address to Load	See	335	54		280	54		ns
T_{S3}	Clear to Load	Switching	335	14		280	14		ns
T_{S4}	Control to Line Clock	Time	50	-10		40	-10		ns
T_{S5}	Line Clock to Load	Waveforms	1140	156		950	156		ns
T_{S6}	Address to Address Latch		50	6		40	6		ns
	Hold Time								
T_{H1}	Load from Dot Clock		5	-6		0	-6		ns
T_{H2}	Address from Load		0	-14		0	-14		ns
T_{H3}	Control from Line Clock		120	23		100	23		ns
T_{H4}	Address from Address Latch		50	3		40	3		ns

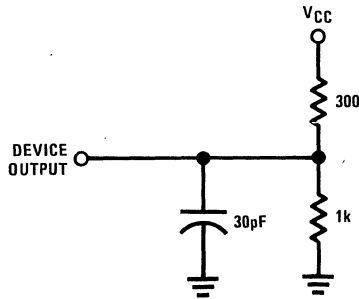
AC Electrical Characteristics (Continued) (Note 2)

SYM	PARAMETER	CONDITIONS	DM76S64			DM86S64			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
TW1	Pulse Width Line Clock		50	12		40	12		ns
TW2	Clear		50	6		40	6		ns
TW3	Dot Clock		25	12		20	12		ns
TW4	Load		40	8		30	8		ns
TW5	Address Latch		50	22		40	22		ns
fMAX	Clock Frequency		18	35		22	35		MHz

Note 1: Absolute maximum ratings are those values beyond which the device may be permanently damaged. They do not mean that the device may be operated at these values.

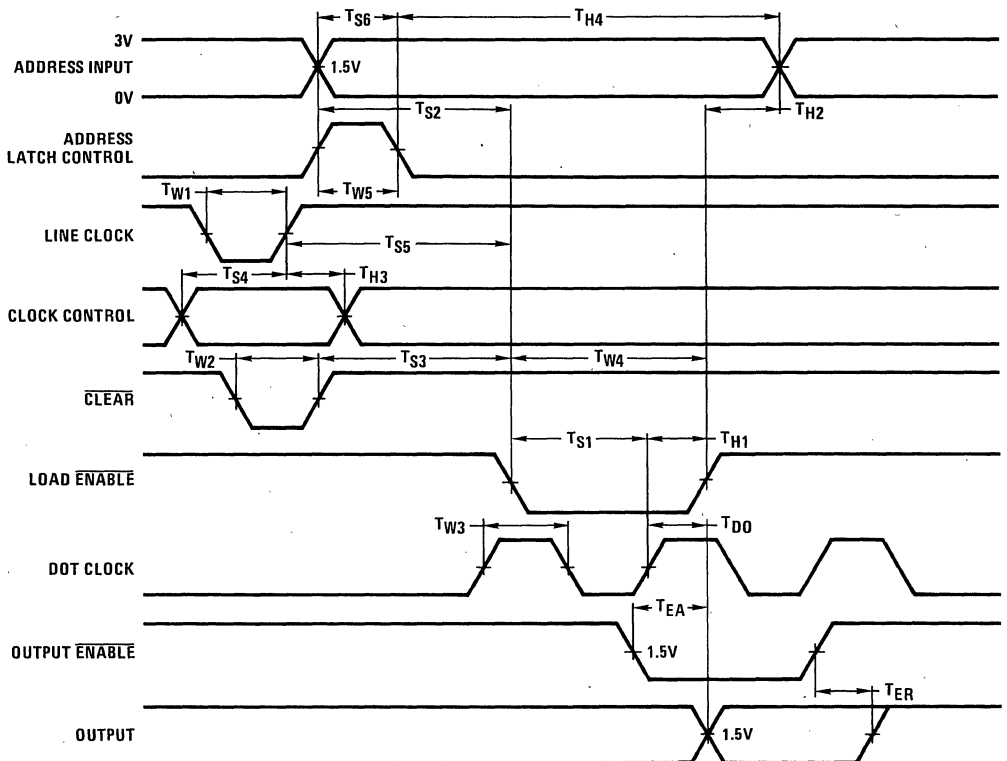
Note 2: These limits apply over the entire operating range unless stated otherwise. All typical values are for $V_{CC} = 5V$ and $T_A = 25^\circ C$.

Standard Test Load



- Input waveforms are supplied by a pulse generator having the following characteristics: PRR = 1 MHz, $Z_{OUT} = 50 \Omega$, $t_r < 5 ns$ and $t_f < 5 ns$ (between 1.0V and 2.0V).
- T_{DO} is measured with output enable at a steady low level.

Switching Time Waveforms



Truth Tables



A) ADDRESS LATCH

ADDRESS LATCH CONTROL	FUNCTION PERFORMED
0	Latched
1	Fall Through

B) OUTPUT

OUTPUT ENABLE	STATE OF THE OUTPUT
1	Output Hi-Z
0	Data Out

C) 4-BIT LINE COUNTER

CLOCK CONTROL	LINE CLOCK	CLEAR	LINE COUNTER
H		H	Increment line counter
X	X	L	Asynchronous clear resets counter
L	X	H	Clock inhibited
H		H	No change on high-to-low clock edge

X = Don't care

Definitions

A0–A5: Character address. A 6-bit code which selects 1 of the 64 characters in the font.

Clear: Active low clear for mod 16 row counter, (can be used to truncate mod 16 counter).

Line Clock: Clock that advances the line counter. Advances counter on the low-to-high transition.

Clock Control: Enables line clock when high and disables line clock when low.

Load Enable: Active low load command which routes data from the character ROM to the "D" inputs of the 7-bit shift register.

Dot Clock: A low-to-high transition of the dot clock loads the shift register if load enable is low or shifts data if load enable is high.

Output Enable: An active low output enable. When high the output is in the Hi-Z state.

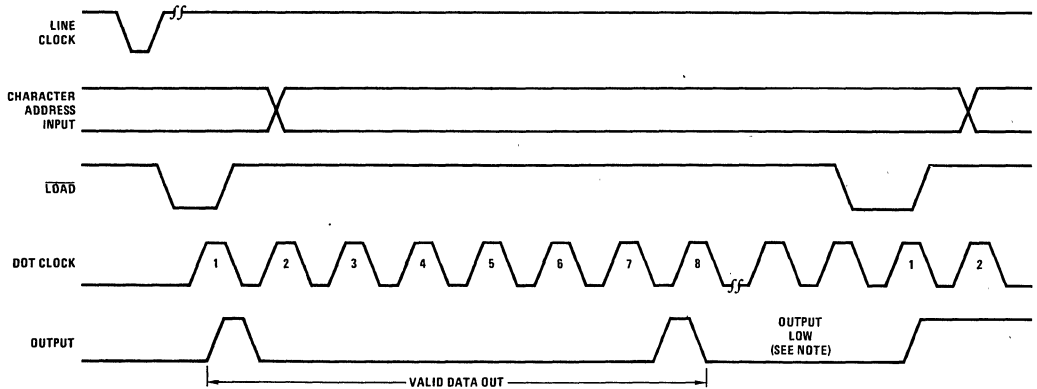
Output: A TTL TRI-STATE output buffer.

Functional Description

To select a character, a 6-bit binary word must be present at the address inputs A0–A5 when the address latch control is high. This address can be latched by bringing the address latch control signal low after a 40 ns set-up time. When the clear input receives a low pulse, the counter is reset to zero. The shift register can be loaded (T_{S2} ns) after the character is addressed. Data, representing 1 horizontal line of the addressed character, is available at the output when the load enable input is brought low. As shown in *Figure 1*, valid data arrives serially at the output. Dot clock pulses beyond that required to shift out 1 line of the

character will add lows to the end of character. This provides a horizontal spacing between characters.

Figure 2 shows how the counter sequences through the rows of addressed lines with the application of clock pulses at the line clock input. Any additional line clocks beyond that required to display the character will put a vertical space between characters. This spacing can be truncated by bringing the clear input low. Detailed system application information is contained in application note AN-167 available from National.



Note. Output goes and stays low following the leading edge of the eighth Dot-Clock pulse until Load enable is enabled again and new parallel data is loaded into the shift register.

FIGURE 1. Character Cycle

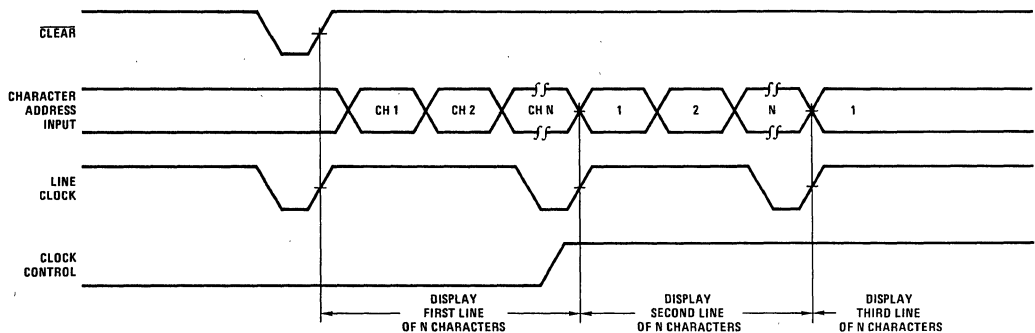


FIGURE 2. Line Cycle

Functional Description (Continued)

A two character display example is shown in *Figure 3* and a typical system timing waveform is shown in *Figure 4*.

A chip select input is provided for expansion of the character font. The various standard fonts are shown in *Figures 5, 6, 7, 8, 9 and 10*. Descending characters in the 5 x 7 fonts are shifted by virtue of their placement in the matrix. Descending characters in the 7 x 9 fonts are shifted (by the on-chip line shifter/counter) the number of lines indicated by the number in the upper left hand corner of the character drawings in the figures.

Character Cycle — ROM data corresponding to 1 line of characters is loaded into the shift register TS2 after the ROM is addressed. When load enable goes low, ROM data is allowed to be present at the D input of

the shift register via the MUX. The first bit of the ROM data is transferred to the output at the next low-to-high transition of the dot clock. After load enable goes back high, the second to seventh clock pulses shift out the rest of the selected row of the addressed character. Additional clock pulses will shift out low data used for spacing.

Line Cycle — The line counter is a mod 16 counter. A low-to-high transition of the line clock advances the line counter to the next count. If, for any reason, the counts need to be truncated, a low signal at the clear input resets the counter to zero. The clock control may be used as a line clock disable. A high signal at the line clock control terminal enables the counter and a low signal disables the line clock.

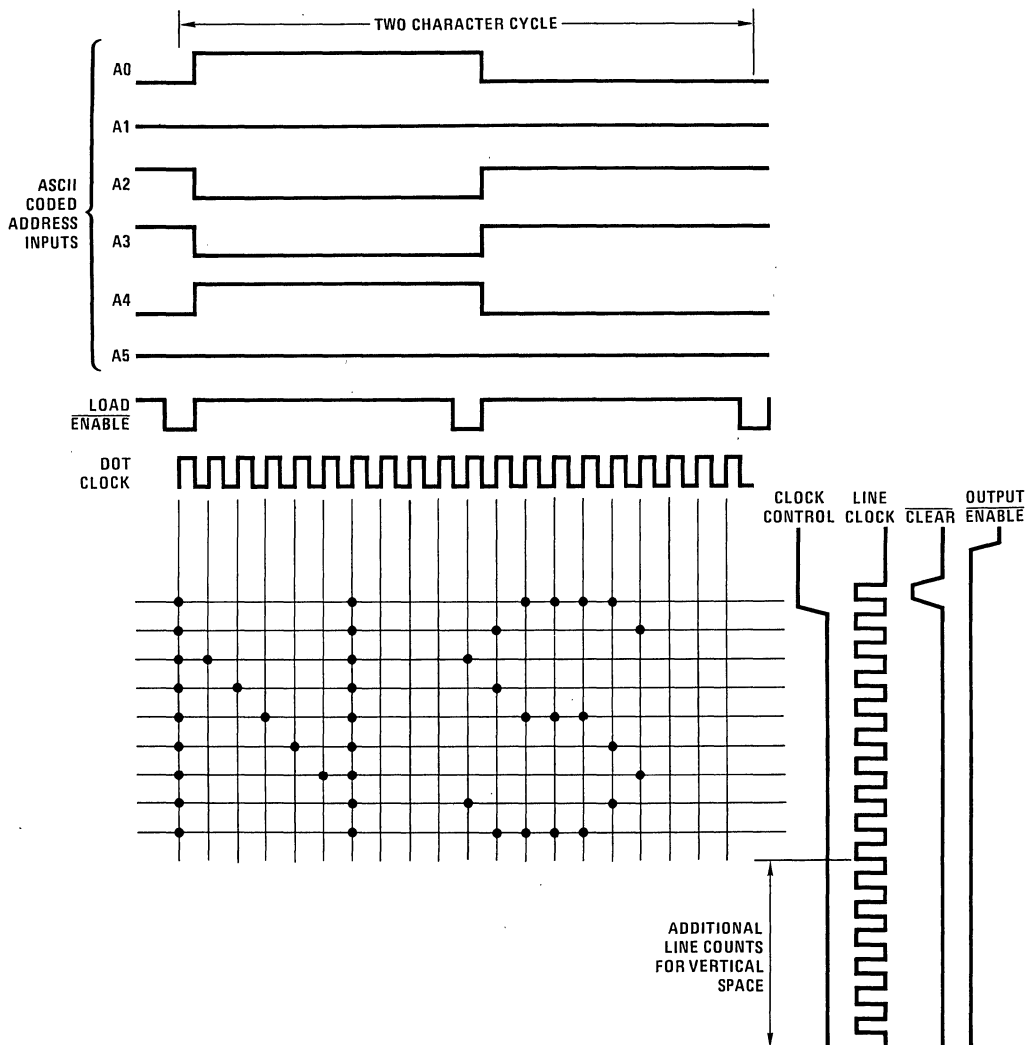
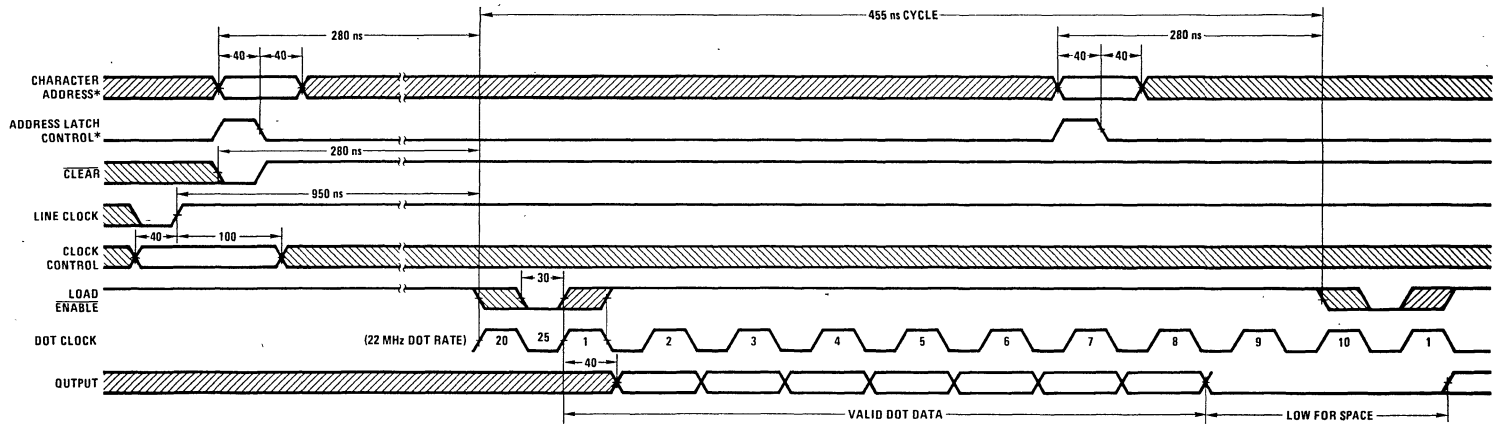


FIGURE 3. Example of Two Characters Display Timing



*Shown here for operation with dynamic memory. For static memory operation the address latch control would be tied high and the character addresses would be stable between each address change occurring 280 ns before the high-to-low transition of Load enable.

FIGURE 4. Typical System Timing Waveform

Functional Description (Continued)

DM76S64/DM86S64

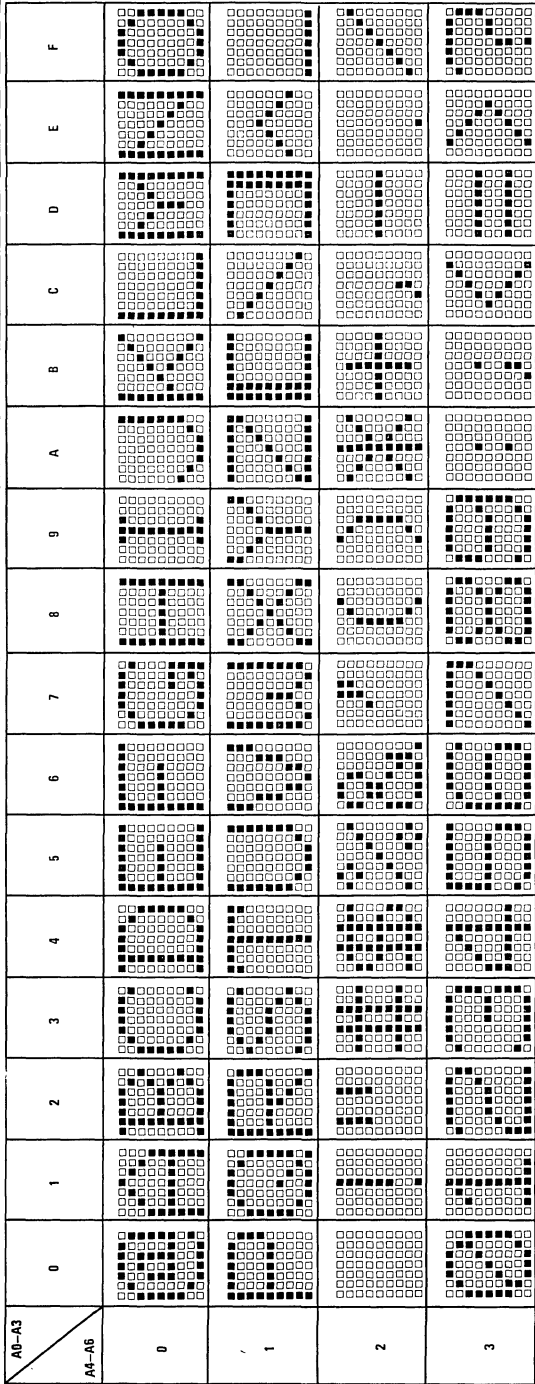


FIGURE 5. DM76S64BWF/DM86S64BWF

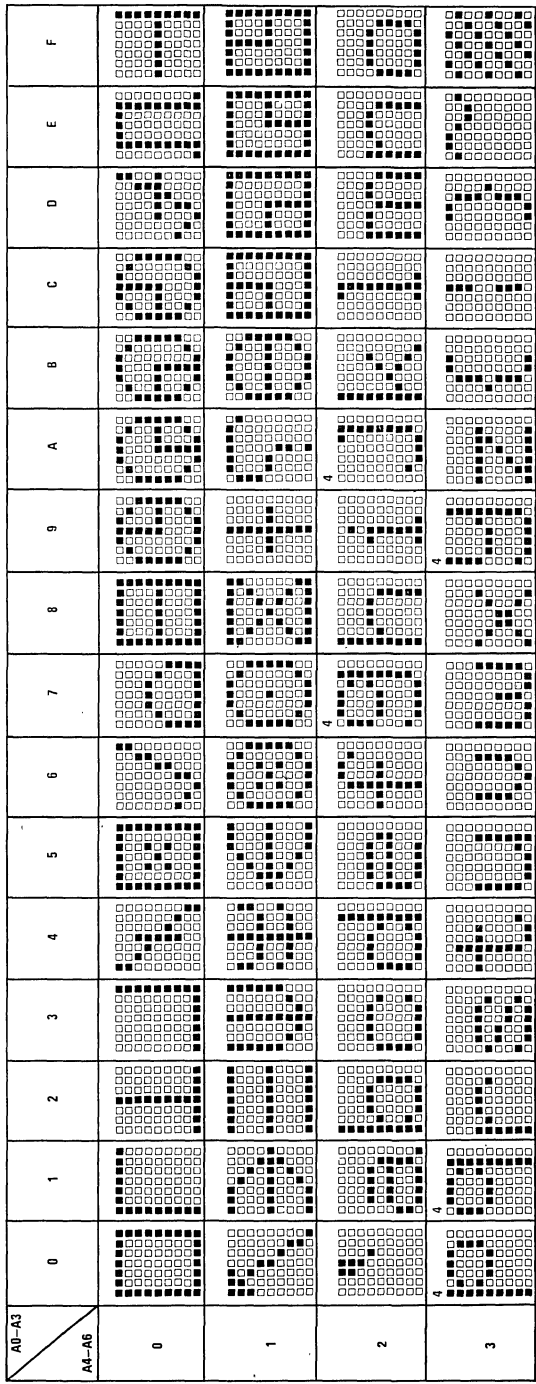


FIGURE 6. DM76S64CAE/DM86S64CAE

Functional Description (Continued)

A0-A3 A4-A6	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
0																
1																
2																
3																

FIGURE 7. DM76S64CAB/DM86S64CAB

A0-A3 A4-A6	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F
0																
1																
2																
3																

FIGURE 8. DM76S64CAH/DM86S64CAH

Functional Description (Continued)

A0-A3 / A4-A5	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F

FIGURE 9. DM76S64CTA/DM86S64CTA

Functional Description (Continued)

A0-A3	0											A	B	C	D	E	F
A4-A5	0																
	1																
	2																
	3																

FIGURE 10. DM76S64CTB/DM86S64CTB

DM76S128/DM86S128 Bipolar Character Generator

General Description

The DM76S128/DM86S128 is a 128-character bipolar character generator with serial output designed primarily for the CRT display marketplace, and packaged in a standard 16-pin DIP. The DM76S128/DM86S128 incorporates several CRT system level functions, as well as a 7 x 9 or 5 x 7 row scan character font. The DM76S128/DM86S128 performs the system functions of parallel to serial shifting, character address latching, character spacing and character line spacing. These system functions have required extra packages in the past.

Shifted characters can be generated by the on-chip adder/subtractor.

The clear input and the load enable input are active low. Load enable is synchronous with the dot clock. Both the line clock and the dot clock are positive edge-triggered. When the address latch control signal is high,

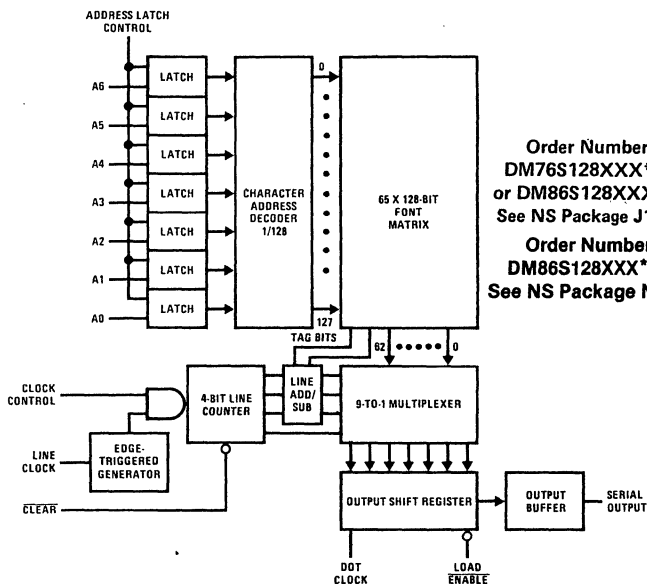
the character addresses "fall through" the latch. And when the address latch control signal goes low, the character addresses are latched.

Features

- 128 character—row scan
- 5 x 7 or 7 x 9 font
- Custom fonts available with shift options
- Serial output
- 16-pin package
- 35 MHz typical clock rate
- On-chip input latches
- On-chip shift register
- On-chip dot blanking
- On-chip row blanking
- Low power—400 mW typical

	7 x 9	5 x 7	FONT	PACKAGE
DM76S128CNC/DM86S128CNC	X		Upper and Shifted Lower Case Block	N, J
DM76S128CND/DM86S128CND		X	Upper and Lower Case Block	N, J
DM76S128CQH/DM86S128CQH	X		ASCII CHARACTER SET	N, J
DM76S128CQJ/DM86S128CQJ		X	ASCII CHARACTER SET	N, J

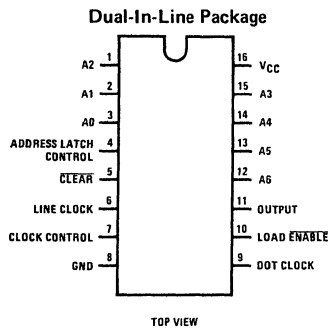
Block Diagram



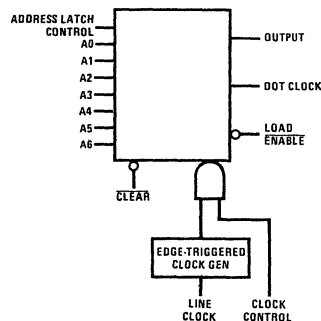
Order Number
DM76S128XXX*/J
or DM86S128XXX*/J
See NS Package J16A

Order Number
DM86S128XXX*/N
See NS Package N16A

Connection Diagram



Logic Symbol



*alpha pattern designators

Absolute Maximum Ratings (Note 1)

Supply Voltage	-0.5V to +7V
Input Voltage	-1.5V to +5.5V
Output Voltage	-0.5V to +5.5V
Storage Temperature	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V_{CC})			
DM76S128	4.5	5.5	V
DM86S128	4.75	5.25	V
Ambient Temperature (T_A)			
DM76S128	-55	+125	°C
DM86S128	0	+70	°C
Logical "0" Input Voltage (Low)	0	0.8	V
Logical "1" Input Voltage (High)	2.0	5.5	V

DC Electrical Characteristics (Note 2)

SYM	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
I _{IL}	Input Load Current	$V_{CC} = \text{Max}, V_{IN} = 0.45V$			-800	μA
I _{IH}	Input Leakage Current	$V_{CC} = \text{Max}, V_{IN} = 2.4V$			40	μA
I _I	Input Leakage Current	$V_{CC} = \text{Max}, V_{IN} = 5.5V$			1	mA
V _{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}, I_{OL} = 16 \text{ mA}$		0.35	0.45	V
V _{OH}	Output Voltage High	$I_{OH} = -2 \text{ mA}$	2.4	3.2		V
V _{IL}	Low Level Input Voltage	$V_{CC} = \text{Min}$			0.80	V
V _{IH}	High Level Input Voltage	$V_{CC} = \text{Min}$	2.0			V
V _C	Input Clamp Voltage	$V_{CC} = \text{Min}, I_{IN} = -12 \text{ mA}$		-0.8	-1.5	V
C _{IN}	Input Capacitance	$V_{CC} = 5V, V_{IN} = 2V, T_A = 25^\circ C,$ 1 MHz		4.0		pF
C _O	Output Capacitance	$V_{CC} = 5V, V_O = 2V, T_A = 25^\circ C,$ 1 MHz		6.0		pF
I _{CC}	Power Supply Current	$V_{CC} = \text{Max}, \text{All Inputs Grounded},$ Output Open		100	140	mA
I _{SC}	Output Short-Circuit Current	$V_O = 0V, V_{CC} = \text{Max}$	-15		-70	mA

AC Electrical Characteristics

DM76S128: $T_A = -55^\circ C$ to $+125^\circ C$, $V_{CC} = 4.5V$ to $5.5V$, $C_L = 50 \text{ pF}$.DM86S128: $T_A = 0^\circ C$ to $+70^\circ C$, $V_{CC} = 4.75V$ to $5.25V$, $C_L = 50 \text{ pF}$.

SYM	PARAMETER	DM76S128			DM86S128			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
T _{DO}	Access Time							
	Dot Clock to Output		25	50		25	40	ns
	Set Up Time							
T _{S1}	Load to Dot Clock	25	7		20	7		ns
T _{S2}	Address to Load	335	54		280	54		ns
T _{S3}	Clear to Load	335	14		280	14		ns
T _{S4}	Control to Line Clock	50	-10		40	-10		ns
T _{S5}	Line Clock to Load	1140	156		950	156		ns
T _{S6}	Address to Address Latch	50	6		40	6		ns
	Hold Time							
T _{H1}	Load from Dot Clock	5	-6		0	-6		ns
T _{H2}	Address from Load	0	-14		0	-14		ns
T _{H3}	Control from Line Clock	120	23		100	23		ns
T _{H4}	Address from Address Latch	50	3		40	3		ns

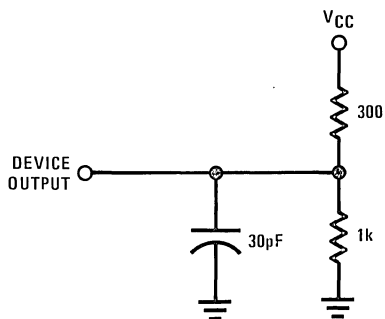
AC Electrical Characteristics (Continued) (With standard load) (Note 2)

SYM	PARAMETER	DM76S128			DM86S128			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
TW1	Line Clock	50	12		40	12		ns
TW2	Clear	50	6		40	6		ns
TW3	Dot Clock	25	12		20	12		ns
TW4	Load	40	8		30	8		ns
TW5	Address Latch	50	22		40	22		ns
fMAX	Clock Frequency	18	35		22	35		MHz

Note 1: Absolute maximum ratings are those values beyond which the device may be permanently damaged. They do not mean that the device may be operated at these values.

Note 2: These limits apply over the entire operating range unless stated otherwise. All typical values are for $V_{CC} = 5V$ and $T_A = 25^\circ C$.

Standard Test Load



- Input waveforms are supplied by a pulse generator having the following characteristics: PRR = 1 MHz, $Z_{OUT} = 50 \Omega$, $t_r < 5 \text{ ns}$ and $t_f < 5 \text{ ns}$ (between 1.0V and 2.0V).

Truth Tables

A) ADDRESS LATCH

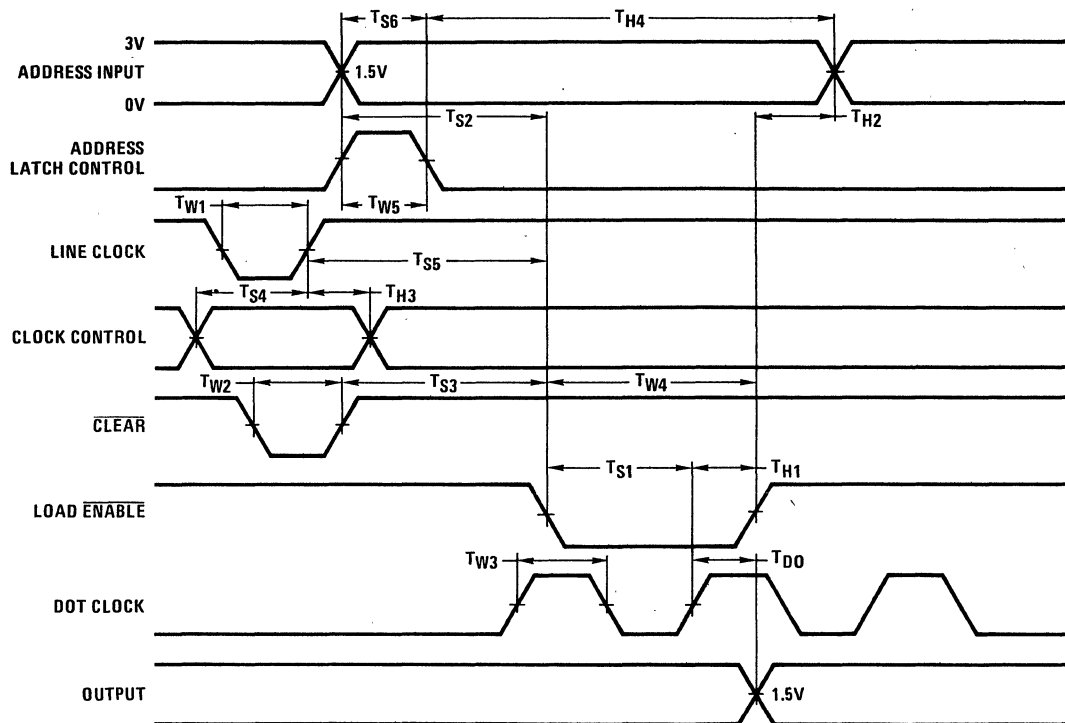
ADDRESS LATCH CONTROL	FUNCTION PERFORMED
0	Latched
1	Fall Through

B) 4-BIT LINE COUNTER

CLOCK CONTROL	LINE CLOCK	CLEAR	LINE COUNTER
H		H	Increment line counter
X	X	L	Asynchronous clear resets counter
L	X	H	Clock inhibited
H		H	No change on high-to-low clock edge

X = Don't care

Switching Time Waveforms



Definitions

A0–A6: Character address. A 7-bit code which selects 1 of the 128 characters in the font.

Clear: Active low clear for mod 16 row counter, (can be used to truncate mod 16 counter).

Line Clock: Clock that advances the line counter. Advances counter on the low-to-high transition.

Clock Control: Enables line clock when high and disables line clock when low.

Load Enable: Active low load command which routes data from the character ROM to the "D" inputs of the 7-bit shift register.

Dot Clock: A low-to-high transition of the dot clock loads the shift register if load enable is low or shifts data if load enable is high.

Output: A TTL BI-STATE output buffer.

Functional Description

To select a character, a 7-bit binary word must be present at the address inputs A0–A6 when the address latch control is high. This address can be latched by bringing the address latch control signal low after a 40 ns set-up time. When the clear input receives a low pulse, the counter is reset to zero. The shift register can be loaded (T_{S2} ns) after the character is addressed. Data, representing one horizontal line of the addressed character, is available at the output when the load enable input is brought low. As shown in *Figure 1*, valid data arrives serially at the output. Dot clock pulses beyond that required to shift out one line of the character will add lows to the end of character. This provides a horizontal spacing between characters.

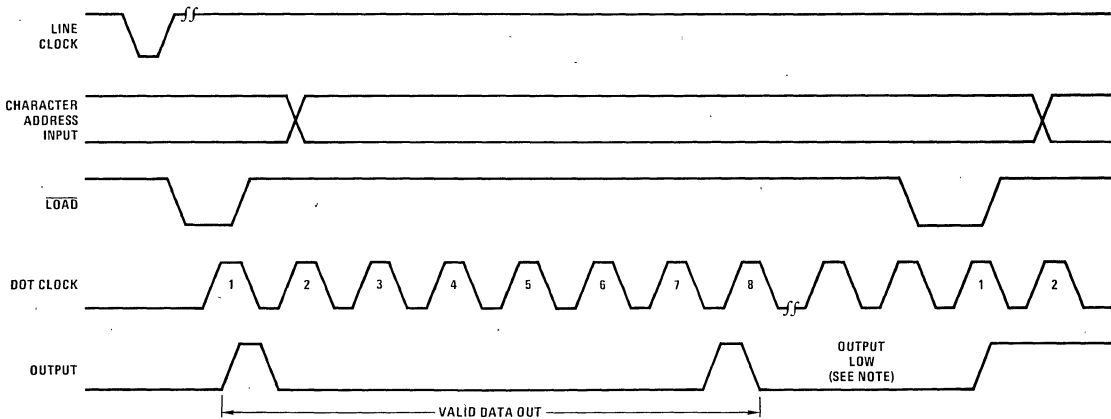
Figure 2 shows how the counter sequences through the rows of addressed lines with the application of clock pulses at the line clock input. Any additional line clocks beyond that required to display the character will put a vertical space between characters. This spacing can be truncated by bringing the clear input low.

A two character display example is shown in *Figure 3* and a typical system timing waveform is shown in *Figure 4*. The standard fonts are shown in *Figures 5, 6, 7 and 8*. Descending characters in the 5 x 7 fonts are

shifted by virtue of their placement in the matrix. Descending characters in the 7 x 9 fonts are shifted (by the on-chip line shifter/counter) the number of lines indicated by the number in the upper left hand corner of the character drawings in the figures.

Character Cycle – ROM data corresponding to one line of characters is loaded into the shift register T_{S2} after the ROM is addressed. When load enable goes low, ROM data is allowed to be present at the D input of the shift register via the MUX. The first bit of the ROM data is transferred to the output at the next low-to-high transition of the dot clock. After load enable goes back high, the second to seventh clock pulses shift out the rest of the selected row of the addressed character. Additional clock pulses will shift out low data used for spacing.

Line Cycle – The line counter is a mod 16 counter. A low-to-high transition of the line clock advances the line counter to the next count. If, for any reason, the counts need to be truncated, a low signal at the clear input resets the counter to zero. The clock control may be used as a line clock disable. A high signal at the line clock control terminal enables the counter and a low signal disables the line clock.



Note. Output goes and stays low following the leading edge of the eighth Dot-Clock pulse until Load enable is enabled again and new parallel data is loaded into the shift register.

FIGURE 1. Character Cycle

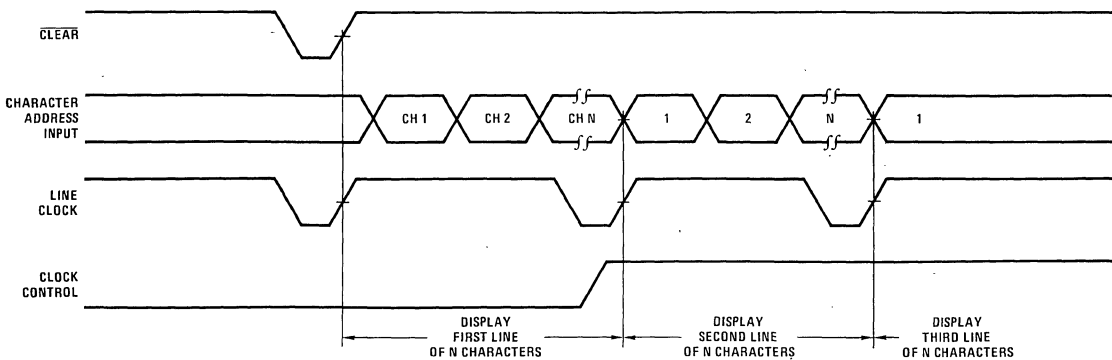


FIGURE 2. Line Cycle

Functional Description (Continued)

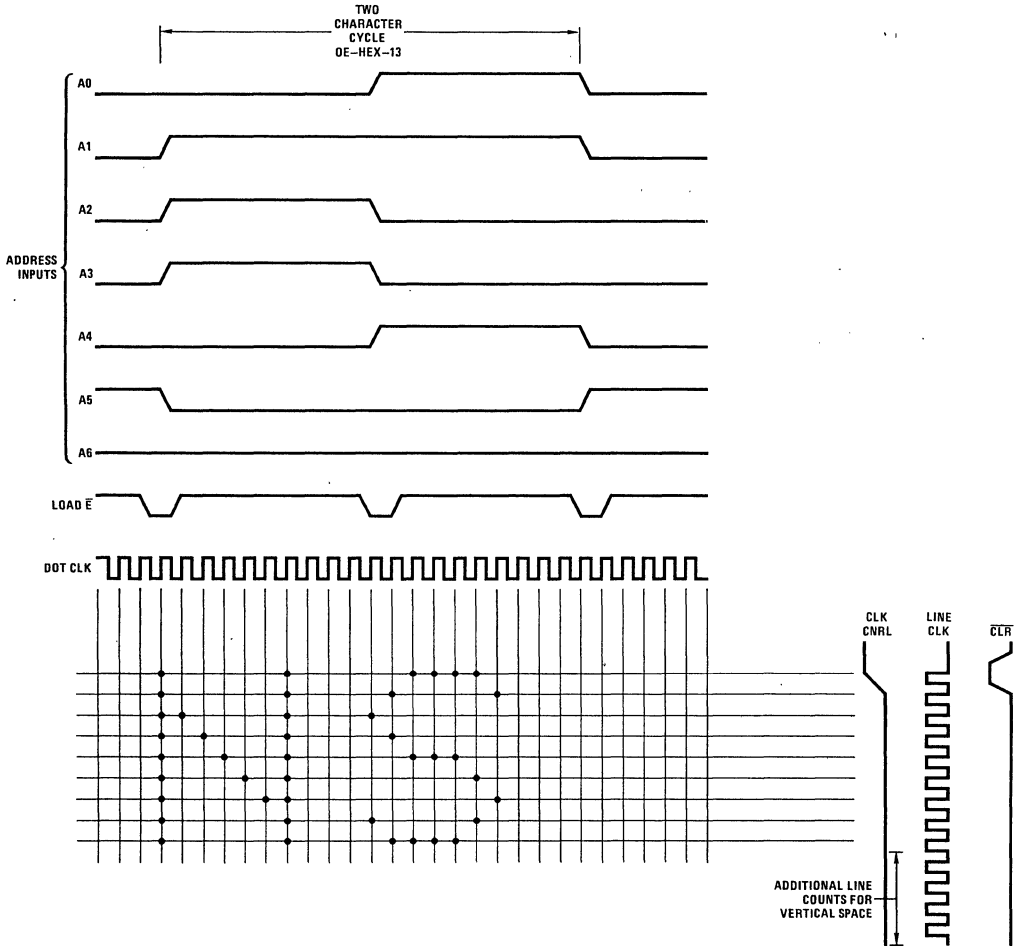
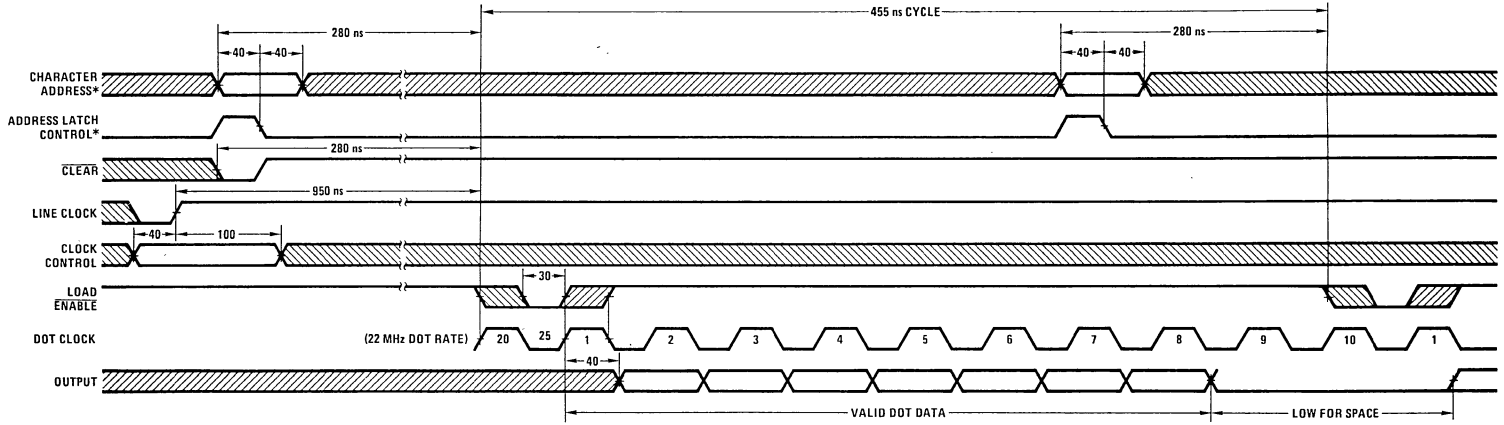


FIGURE 3. Example, Two Character Display Timing – DM86S128CNC



*Shown here for operation with dynamic memory. For static memory operation the address latch control would be tied high and the character addresses would be stable between each address change occurring 280 ns before the high-to-low transition of Load enable.

FIGURE 4. Typical System Timing Waveform

Functional Description (Continued)

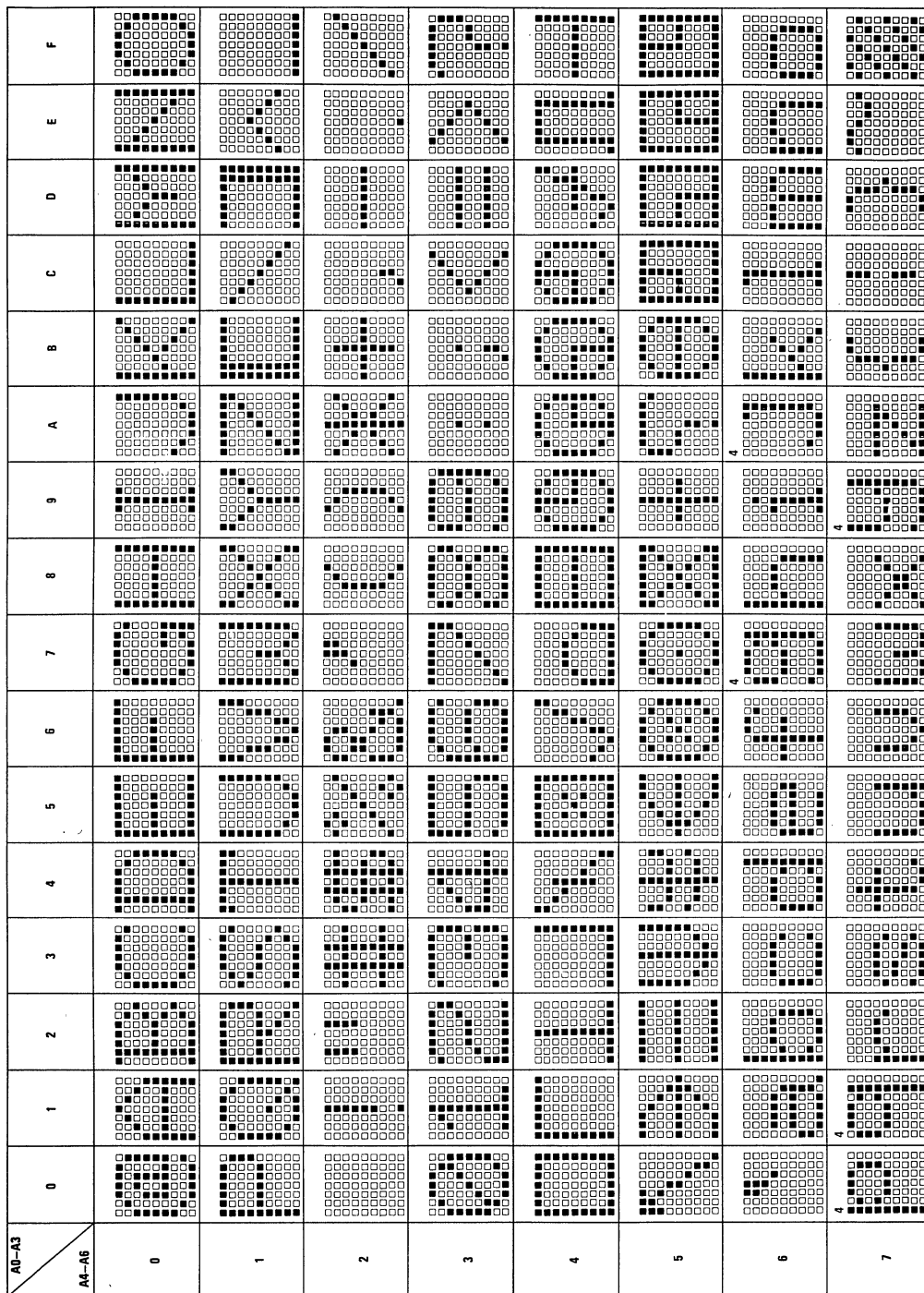


FIGURE 5. DM86S128CNC

Functional Description (Continued)

DM76S128/DM86S128

A0-A3 A4-A8	0								
	1								
	2								
	3								
	4								
	5								
	6								
	7								
	8								
	9								
	A								
	B								
	C								
	D								
	E								
	F								

FIGURE 6. DM86S128CND

Functional Description (Continued)

A0-A3 A4-A7	0	1	2	3	4	5	6	7
0								
1								
2								
3								
4								
5								
6								
7								
8								
9								
A								
B								
C								
D								
E								
F								

FIGURE 7. DM86S128CQJ

Functional Description (Continued)

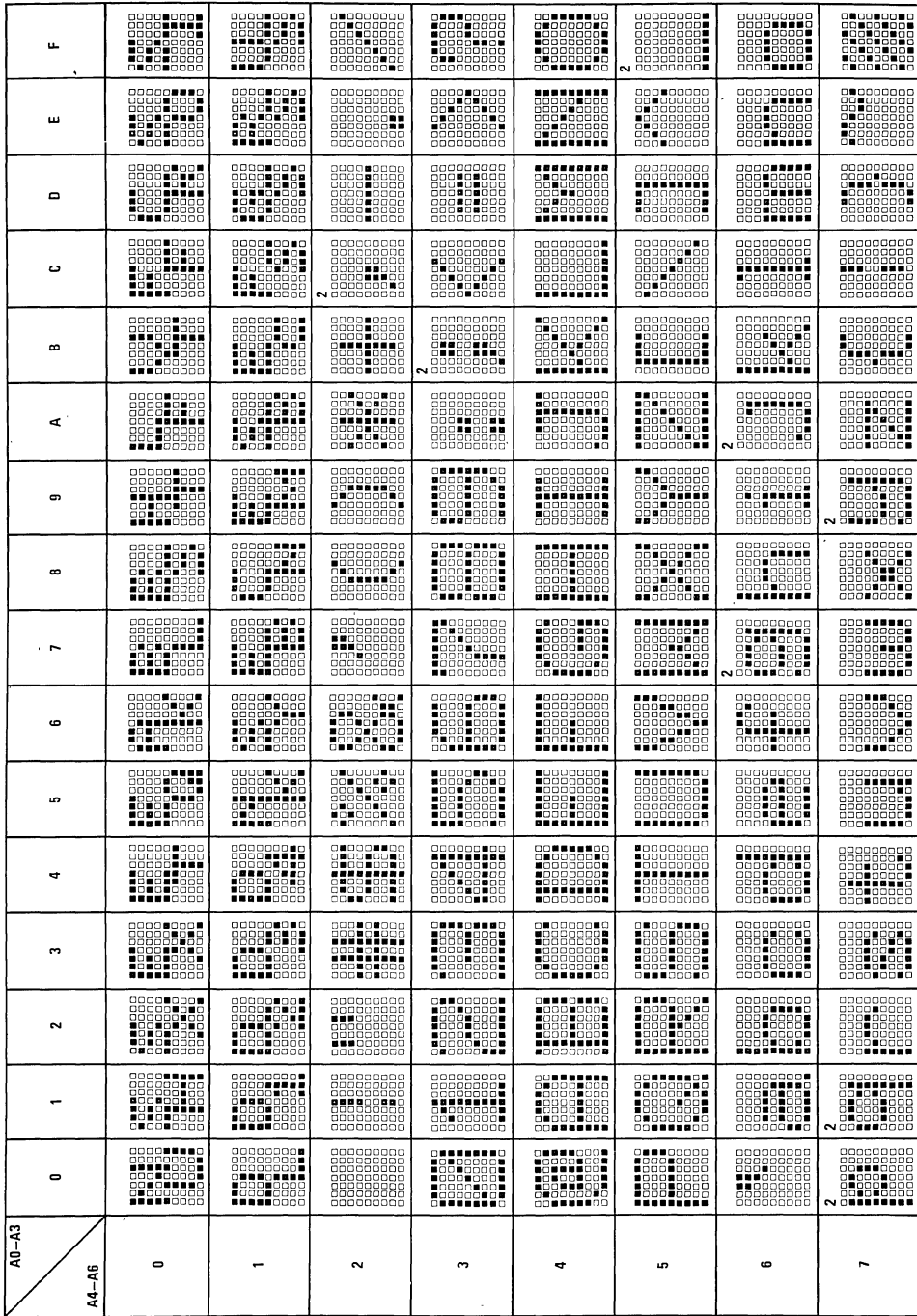


FIGURE 8. DM86S128CQH



Section 22 Bipolar and ECL RAMs

22

DEVICE	DESCRIPTION	PAGE NUMBER
DM54S189/DM74S189	64-Bit (16 × 4) TRI-STATE RAM	22-3
DM54S289/DM74S289	64-Bit Open-Collector RAM	22-3
DM54S189A/DM74S189A	High Speed 64-Bit TRI-STATE RAM	22-3
DM75S06/DM85S06	Open-Collector 64-Bit (16 × 4) RAM	22-10
DM75S07/DM85S07	TRI-STATE 64-Bit (16 × 4) RAM	22-10
DM75S07A/DM85S07A	High Speed TRI-STATE Non-Inverting 64-Bit (16 × 4) RAM	22-10
DM77S401/DM87S401, DM77S402/DM87S402	First-In, First-Out (FiFo) 64 × 4, 64 × 5 Serial Memories	22-16
DM77S401A/DM87S401A, DM77S402A/DM87S402A	First-In, First-Out (FiFo) 64 × 4, 64 × 5 Serial Memories	22-20
DM75S68/DM85S68	16 × 4 Edge Triggered Registers	22-24
IDM29705/29705A	16-Word by 4-Bit Two-Port RAM/Register File	22-27
DM10414, DM10414A	256 × 1 ECL Random Access Memory	22-32
DM10415, DM10415A	1024 × 1 ECL Random Access Memory	22-37
DM10422	1024-Bit (256 × 4) ECL RAM	22-42
DM10422A	1024-Bit (256 × 4) ECL RAM	22-45
DM10470	Standard 4096-Bit (4096 × 1) ECL RAM	22-48
DM10470A	High Speed 4096-Bit (4096 × 1) ECL RAM	22-48
DM10470L	Low Power 4096-Bit (4096 × 1) ECL RAM	22-48
DM10474/DM10474A	(1024 × 4) 4096-Bit, 10k ECL RAM	22-53

DM54S189/DM74S189 64-Bit (16 × 4) TRI-STATE® RAM
DM54S289/DM74S289 64-Bit Open-Collector RAM
DM54S189A/DM74S189A High Speed 64-Bit TRI-STATE RAM
General Description

These 64-bit active-element memories are monolithic Schottky-clamped transistor-transistor logic (TTL) arrays organized as 16 words of 4 bits each. They are fully decoded and feature a chip-enable input to simplify decoding required to achieve the desired system organization. The memories feature PNP input transistors that reduce the low level input current requirement to a maximum of -0.25 mA, only one-eighth that of a DM54S/DM74S standard load factor. The chip-enable circuitry is implemented with minimal delay times to compensate for added system decoding.

The TRI-STATE output combines the convenience of an open-collector with the speed of a totem-pole output; it can be bus connected to other similar outputs; yet it retains the fast rise time characteristics of the TTL totem-pole output. Systems utilizing data bus lines with a defined pull-up impedance can employ the open-collector DM54S289.

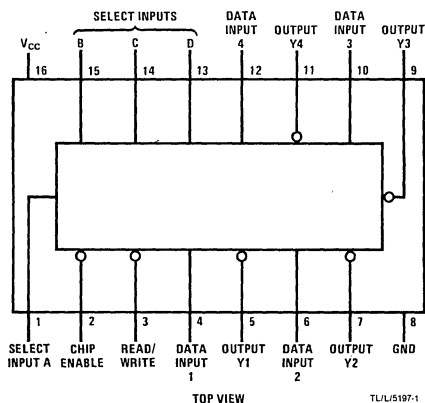
Write Cycle: The complement of the information at the data input is written into the selected location when both the chip-enable input and the read/write input are low. While the read/write input is low, the outputs are in the high-impedance state. When a number of the DM54S189 outputs are bus connected, this high-impedance state will neither load nor drive the bus line, but it will allow the bus line to be driven by another active output or a passive pull-up if desired.

Read Cycle: The stored information (complement of information applied at the data inputs during the write cycle) is available at the outputs when the read/write input is high and the chip-enable is low. When the chip-enable is high, the outputs will be in the high-impedance state.

The fast access time of the DM54S189A makes it particularly attractive for implementing high-performance memory functions requiring access times less than 25 ns. The high capacitive drive capability of the outputs permits expansion without additional output buffering. The unique functional capability of the DM54S189A outputs being at a high-impedance during writing, combined with the data inputs being inhibited during reading, means that both data inputs and outputs can be connected to the data lines of a bus-organized system without the need for interface circuits.

Features

- Schottky-clamped for high speed applications (S189A)
 - access from chip-enable input 17 ns max
 - access from address inputs 25 ns max
- TRI-STATE outputs drive bus-organized systems and/or high capacitive loads (S189, S189A)
- DM54S289/DM74S289 are functionally equivalent and have open-collector outputs
- DM54SXXX is guaranteed for operation over the full military temperature range of -55°C to +125°C
- Compatible with most TTL circuits
- Chip-enable input simplifies system decoding

Connection Diagram
Dual-In-Line Package

Truth Table

Function	Inputs		Output
	Chip-Enable	Read/Write	
Write (Store Complement of Data)	L	L	High-Impedance
Read	L	H	Stored Data
Inhibit	H	X	High-Impedance

H = High Level

L = Low Level

X = Don't Care

**Order Number DM54S189J, DM54S189AJ, DM74S189J,
DM74S189AJ, DM54S289J or DM74S289J**
See NS Package J16A

Order Number DM74S189N, DM74S189AN or DM74S289N
See NS Package N16E

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})			
DM54S189, DM54S289	4.5	5.5	V
DM74S189, DM74S289	4.75	5.25	V
Temperature (T_A)			
DM54S189, DM54S289	-55	+125	°C
DM74S189, DM74S289	0	+70	°C

DM54S189/D74S189, DM54S289/D74S289 Electrical Characteristics

over recommended operating free-air temperature range unless otherwise noted (Notes 2 and 3)

Symbol	Parameter	Conditions		Min	Typ	Max	Units
V_{IH}	High Level Input Voltage			2			V
V_{IL}	Low Level Input Voltage					0.8	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}$	$I_{OH} = -2.0 \text{ mA}$, DM54S189	2.4	3.4		V
			$I_{OH} = -6.5 \text{ mA}$, DM74S189	2.4	3.2		
I_{CEX}	High Level Output Current Open Collector Only	$V_{CC} = \text{Min}$	$V_{OH} = 2.4\text{V}$			40	μA
			$V_{OH} = 5.5\text{V}$			100	
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}$, $I_{OL} = 16 \text{ mA}$	DM54S189, DM54S289			0.5	V
			DM74S189, DM74S289			0.45	
I_{IH}	High Level Input Current	$V_{CC} = \text{Max}$, $V_I = 2.7\text{V}$				25	μA
I_I	High Level Input Current at Maximum Voltage	$V_{CC} = \text{Max}$, $V_I = 5.5\text{V}$				1.0	mA
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max}$, $V_I = 0.45\text{V}$				-250	μA
I_{OS}	Short Circuit Output Current (Note 4)	$V_{CC} = \text{Max}$, $V_O = 0\text{V}$	DM54S189, DM74S189	-30		-100	mA
I_{CC}	Supply Current (Note 5)	$V_{CC} = \text{Max}$			75	110	mA
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}$, $I_I = -18 \text{ mA}$				-1.2	V
I_{OZH}	TRI-STATE Output Current, High Level Voltage Applied	$V_{CC} = \text{Max}$, $V_O = 2.4\text{V}$	DM54S189, DM74S189			50	μA
I_{OZL}	TRI-STATE Output Current, Low Level Voltage Applied	$V_{CC} = \text{Max}$, $V_O = 0.45\text{V}$	DM54S189, DM74S189	-50			μA
C_{IN}	Input Capacitance	$V_{CC} = 5\text{V}$, $V_{IN} = 2\text{V}$, $T_A = 25^\circ\text{C}$, 1 MHz			4.0		pF
C_O	Output Capacitance	$V_{CC} = 5\text{V}$, $V_O = 2\text{V}$, $T_A = 25^\circ\text{C}$, 1 MHz, Output "OFF"			6.0		pF

DM54S189/D74S189 Switching Characteristics

over recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter	Conditions	DM54S189			DM74S189			Units
			Min	Typ (Note 2)	Max	Min	Typ (Note 2)	Max	
t_{AA}	Access Times from Address	$C_L = 30 \text{ pF}$, $R_L = 280\Omega$ (Figure 4)		25	50		25	35	ns
t_{CZH}	Output Enable Time to High Level			12	25		12	17	ns
t_{CZL}	Output Enable Time to Low Level			12	25		12	17	ns
t_{WZH}	Output Enable Time to High Level			13	35		13	25	ns
t_{WZL}	Output Enable Time to Low Level			13	35		13	25	ns

DM54S189/DM74S189 Switching Characteristics (Continued)over recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM54S189			DM74S189			Units
				Min	Typ (Note 2)	Max	Min	Typ (Note 2)	Max	
t_{CHZ}	Output Disable Time from High Level	Disable Times from Chip-Enable	$C_L = 5 \text{ pF}$, $R_L = 280\Omega$ (Figure 4)		12	25		12	17	ns
t_{CLZ}	Output Disable Time from Low Level				12	25		12	17	ns
t_{WHZ}	Output Disable Time from High Level	Disable Times from Read/Write			15	35		15	25	ns
t_{WLZ}	Output Disable Time from Low Level				15	35		15	25	ns
t_{WP}	Width of Write Enable Pulse (Read/Write Low)				25			25		ns
t_{ASW}	Set-Up Time (Figure 1)	Address to Read/Write			0			0		ns
t_{DSW}		Data to Read/Write		25			25		ns	
t_{CSW}		Chip-Enable to Read/Write		0			0		ns	
t_{AHW}	Hold Time (Figure 1)	Address from Read/Write		0			0		ns	
t_{DHW}		Data from Read/Write		0			0		ns	
t_{CHW}		Chip-Enable from Read/Write		0			0		ns	

DM54S289/DM74S289 Switching Characteristicsover recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM54S289			DM74S289			Units
				Min	Typ (Note 2)	Max	Min	Typ (Note 2)	Max	
t_{AA}	Access Times from Address		$C_L = 30 \text{ pF}$, $R_{L1} = 300\Omega$, $R_{L2} = 600\Omega$ (Figure 4)		25	50		25	35	ns
t_{CHL}	Enable Time from Chip-Enable				12	25		12	17	ns
t_{WHL}	Enable Time from Read/Write	Sense Recovery Time from Read/Write			13	35		13	25	ns
t_{CLH}	Disable Time from Chip-Enable				12	25		12	20	ns
t_{WLH}	Disable Time from Read/Write				13	35		13	25	ns
t_{WP}	Width of Write Enable Pulse (Read/Write Low)				25			25		ns
t_{ASW}	Set-Up Time (Figure 2)	Address to Read/Write		0			0		ns	
t_{DSW}		Data to Read/Write		25			25		ns	
t_{CSW}		Chip-Enable to Read/Write		0			0		ns	
t_{AHW}	Hold Time (Figure 2)	Address from Read/Write		0			0		ns	
t_{DHW}		Data from Read/Write		0			0		ns	
t_{CHW}		Chip-Enable from Read/Write		0			0		ns	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to $+125^\circ\text{C}$ temperature range for the DM54S189/289 and across the 0°C to $+70^\circ\text{C}$ range for the DM74S189/289. All typicals are given for $V_{CC} = 5.0\text{V}$ and $T_A = 25^\circ\text{C}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: I_{CC} is measured with all inputs grounded; and the outputs open.

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	- 65°C to + 150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})			
DM54S189(A)/DM54S289	4.5	5.5	V
DM74S189(A)/DM74S289	4.75	5.25	V
Temperature (T_A)			
DM54S189(A)/DM54S289	- 55	+ 125	°C
DM74S189(A)/DM74S289	0	+ 70	°C

DM54S189A/DM74S189A Electrical Characteristics

over recommended operating free-air temperature range unless otherwise noted (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	High Level Input Voltage		2			V
V_{IL}	Low Level Input Voltage				0.8	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}$ $I_{OH} = -2.0 \text{ mA}$ DM54S189A	2.4	3.4		V
			$I_{OH} = -6.5 \text{ mA}$ DM74S189A	2.4	3.2	
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}$ $I_{OL} = 16 \text{ mA}$			0.45	V
			$I_{OL} = 20 \text{ mA}$			
I_{IH}	High Level Input Current	$V_{CC} = \text{Max}, V_I = 2.4 \text{ V}$			10	μA
I_I	High Level Input Current at Maximum Voltage	$V_{CC} = \text{Max}, V_I = 5.5 \text{ V}$			1.0	mA
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max}, V_I = 0.40 \text{ V}$			- 250	μA
I_{OS}	Short Circuit Output Current (Note 4)	$V_{CC} = \text{Max}, V_O = 0 \text{ V}$	- 20		- 90	mA
I_{CC}	Supply Current (Note 5)	$V_{CC} = \text{Max}$		75	100	mA
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}, I_I = -18 \text{ mA}$			- 1.2	V
I_{OZH}	TRI-STATE Output Current, High Level Voltage Applied	$V_{CC} = \text{Max}, V_O = 2.4 \text{ V}$			40	μA
I_{OZL}	TRI-STATE Output Current, Low Level Voltage Applied	$V_{CC} = \text{Max}, V_O = 0.4 \text{ V}$	- 40			μA
C_{IN}	Input Capacitance	$V_{CC} = 5 \text{ V}, V_{IN} = 2 \text{ V}, T_A = 25^\circ\text{C}, 1 \text{ MHz}$		4.0		pF
C_O	Output Capacitance	$V_{CC} = 5 \text{ V}, V_O = 2 \text{ V}, T_A = 25^\circ\text{C}, 1 \text{ MHz}, \text{Output "OFF"}$		6.0		pF

DM54S189A/DM74S189A Switching Characteristics

over recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM54S189A			DM74S189A			Units
				Min	Typ (Note 2)	Max	Min	Typ (Note 2)	Max	
t_{AA}	Access Times from Address		$C_L = 30$ pF, $R_L = 280\Omega$ (Figure 4)		20	30		20	25	ns
t_{CZH}	Output Enable Time to High Level	Access Times from Chip-Enable			11	25		11	17	ns
t_{CZL}	Output Enable Time to Low Level				11	25		11	17	ns
t_{WZH}	Output Enable Time to High Level	Sense Recovery Times from Read/Write			13	35		13	25	ns
t_{WZL}	Output Enable Time to Low Level				13	35		13	25	ns
t_{CHZ}	Output Disable Time from High Level	Disable Times from Chip-Enable	$C_L = 5$ pF, $R_L = 280\Omega$ (Figure 4)		12	25		12	17	ns
t_{CLZ}	Output Disable Time from Low Level				12	25		12	17	ns
t_{WHZ}	Output Disable Time from High Level	Disable Times from Read/Write			15	35		15	25	ns
t_{WLZ}	Output Disable Time from Low Level				15	35		15	25	ns
t_{WP}	Width of Write Enable Pulse (Read/Write Low)				25			20		ns
t_{ASW}	Set-Up Time (Figure 1)	Address to Read/Write		0			0		ns	
t_{DSW}		Data to Read/Write		25			20		ns	
t_{CSW}		Chip-Enable to Read/Write		0			0		ns	
t_{AHW}	Hold Time (Figure 1)	Address from Read/Write		0			0		ns	
t_{DHW}		Data from Read/Write		0			0		ns	
t_{CHW}		Chip-Enable from Read/Write		0			0		ns	

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to $+125^\circ\text{C}$ temperature range for the DM54S189(A) and across the 0°C to $+70^\circ\text{C}$ range for the DM74S189(A). All typicals are given for $V_{CC} = 5.0\text{V}$ and $T_A = 25^\circ\text{C}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: I_{CC} is measured with all inputs grounded; and the outputs open.

DM54S189/DM74S189, DM54S289/DM74S289, DM54S189A/DM74S189A

DM54S189(A)/DM74S189(A) Switching Time Waveforms

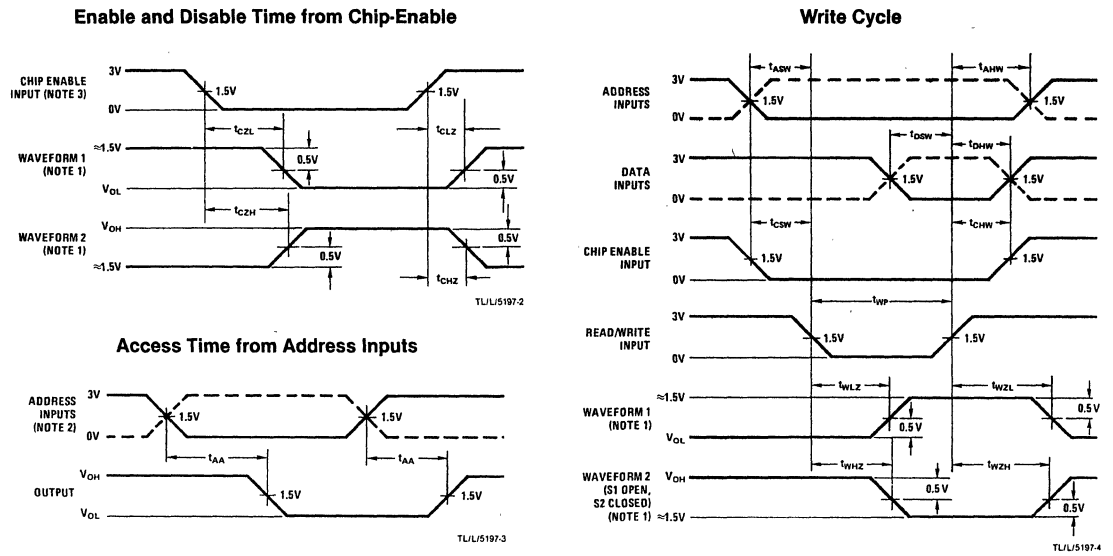


FIGURE 1

Note 1: Waveform 1 is for the output with internal conditions such that the output is low except when disabled. Waveform 2 is for the output with internal conditions such that the output is high except when disabled.

Note 2: When measuring delay times from address inputs, the chip-enable input is low and the read/write input is high.

Note 3: When measuring delay times from chip-enable input, the address inputs are steady-state and the read/write input is high.

Note 4: Input waveforms are supplied by pulse generators having the following characteristics: $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns, $PRR \leq 1$ MHz and $Z_{OUT} = 50\Omega$.

DM54S289/D74S289 Switching Time Waveforms

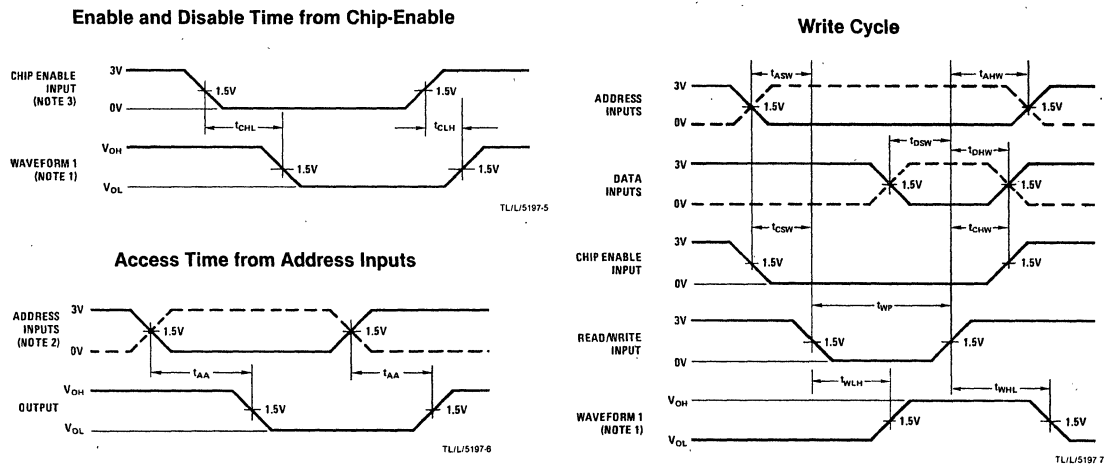


FIGURE 2

Note 1: Waveform 1 is for the output with internal conditions such that the output is low except when disabled.

Note 2: When measuring delay times from address inputs, the chip-enable input is low and the read/write input is high.

Note 3: When measuring delay times from chip-enable input, the address inputs are steady-state and the read/write input is high.

Note 4: Input waveforms are supplied by pulse generators having the following characteristics: $t_r \leq 2.5$ ns, $t_f \leq 2.5$ ns, $PRR \leq 1$ MHz and $Z_{OUT} = 50\Omega$.

Block Diagram

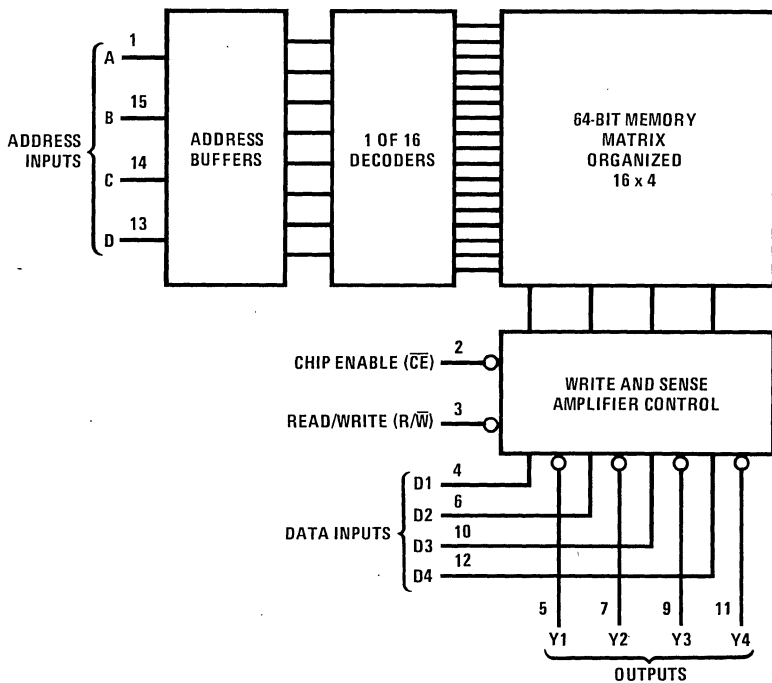
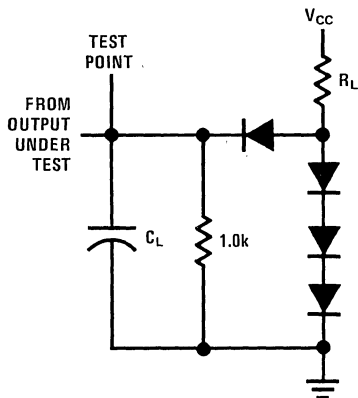


FIGURE 3

TL/L5197 8

AC Test Circuits

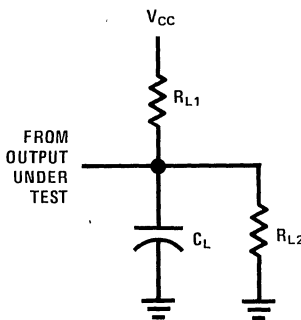
DM54S189(A)/DM74S189(A)



TL/L5197-10

C_L includes probe and jig capacitance.
All diodes are 1N3064.

DM54S289/DM74S289



TL/L5197 9

FIGURE 4

DM54S189/DM74S189, DM54S289/DM74S289, DM54S189A/DM74S189A

**DM75S06/DM85S06 Open-Collector
DM75S07/DM85S07 TRI-STATE
DM75S07A/DM85S07A High Speed TRI-STATE
Non-Inverting, 64-Bit (16 x 4) RAMs**

General Description

These 64-bit active-element memories are monolithic Schottky-clamped transistor-transistor logic (TTL) arrays organized as 16 words of 4 bits each. They are fully decoded and feature a chip-enable input to simplify decoding required to achieve the desired system organization. The memories feature PNP input transistors that reduce the low level input current requirement to a maximum of -0.25 mA, only one-eighth that of a DM54S/DM74S standard load factor. The chip-enable circuitry is implemented with minimal delay times to compensate for added system decoding.

The TRI-STATE output combines the convenience of an open-collector with the speed of a totem-pole output; it can be bus-connected to other similar outputs; yet it retains the fast rise time characteristics of the TTL totem-pole output. Systems utilizing data bus lines with a defined pull-up impedance can employ the open-collector DM75S06.

Write Cycle: The information at the data input is written into the selected location when both the chip-enable input and the read/write input are low. While the read/write input is low, the outputs are in the high-impedance state. When a number of the DM85S07 outputs are bus-connected, this high-impedance state will neither load nor drive the bus line, but it will allow the bus line to be driven by another active output or a passive pull-up if desired.

Read Cycle: The stored information is available at the outputs when the read/write input is high and the chip-

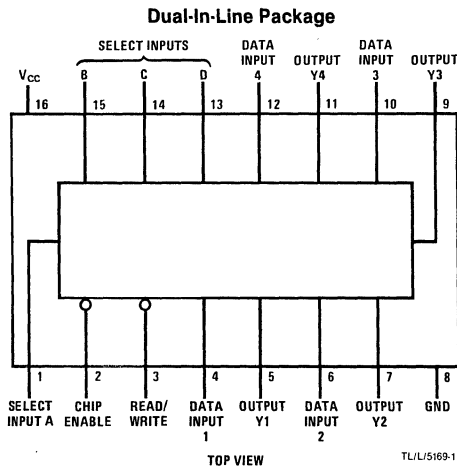
enable is low. When the chip-enable is high, the outputs will be in the high-impedance state.

The fast access time of the DM75S07A makes it particularly attractive for implementing high-performance memory functions requiring access times less than 25 ns. The high capacitive drive capability of the outputs permits expansion without additional output buffering. The unique functional capability of the DM75S07 outputs being at a high-impedance during writing, combined with the data inputs being inhibited during reading, means that both data inputs and outputs can be connected to the data lines of a bus-organized system without the need for interface circuits.

Features

- Schottky-clamped for high speed applications (75S07A)
 - access from chip-enable input 17 ns max
 - access from address inputs 25 ns max
- TRI-STATE outputs drive bus-organized systems and/or high capacitive loads
- DM75S06, DM85S06 are functionally equivalent and have open-collector outputs
- DM75SXX is guaranteed for operation over the full military temperature range of -55°C to +125°C
- Compatible with most TTL logic circuits
- Chip-enable input simplifies system decoding

Connection Diagram



Truth Table

Function	Inputs		Output
	Chip-Enable	Read/Write	
Write	L	L	High-Impedance
Read	L	H	Stored Data
Inhibit	H	X	High-Impedance

H = High Level
L = Low Level
X = Don't Care

**Order Number DM75S06J, DM75S07J, DM75S07AJ,
DM85S06J, DM85S07J or DM85S07AJ
See NS Package J16A**

**Order Number DM85S06N, DM85S07N or DM85S07AN
See NS Package N16E**

Absolute Maximum Ratings (Note 1)

Supply Voltage, V_{CC}	7.0V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})			
DM75S06/DM75S07(A)	4.5	5.5	V
DM85S06/DM85S07(A)	4.75	5.25	V
Temperature (T_A)			
DM75S06/DM75S07(A)	-55	+125	°C
DM85S06/DM85S07(A)	0	+70	°C

Electrical Characteristics

over recommended operating free-air temperature range unless otherwise noted (Notes 2 and 3)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IH}	High Level Input Voltage		2			V
V_{IL}	Low Level Input Voltage				0.8	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}$ $I_{OH} = -2.0 \text{ mA}$, DM75S07(A) $I_{OH} = -5.2 \text{ mA}$, DM85S07(A)	2.4	3.4		V
I_{CEX}	High Level Output Current Open-Collector Only	$V_{CC} = \text{Min}$ $V_{OH} = 2.4\text{V}$ $V_{OH} = 5.5\text{V}$			40	μA
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}$ $I_{OL} = 16 \text{ mA}$ $I_{OL} = 20 \text{ mA}$			0.45	V
I_{IH}	High Level Input Current	$V_{CC} = \text{Max}$, $V_I = 2.4\text{V}$			10	μA
I_I	High Level Input Current at Maximum Voltage	$V_{CC} = \text{Max}$, $V_I = 5.5\text{V}$			1.0	mA
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max}$, $V_I = 0.40\text{V}$			-250	μA
I_{OS}	Short Circuit Output Current (Note 4)	$V_{CC} = \text{Max}$, $V_O = 0\text{V}$ DM75S07(A), DM85S07(A)	-30		-90	mA
I_{CC}	Supply Current (Note 5)	$V_{CC} = \text{Max}$		75	100	mA
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}$, $I_I = -18 \text{ mA}$			-1.2	V
I_{OZH}	TRI-STATE Output Current, High Level Voltage Applied	$V_{CC} = \text{Max}$, $V_O = 2.4\text{V}$ DM75S07(A), DM85S07(A)			40	μA
I_{OZL}	TRI-STATE Output Current, Low Level Voltage Applied	$V_{CC} = \text{Max}$, $V_O = 0.4\text{V}$ DM75S07(A), DM85S07(A)	-40			μA
C_{IN}	Input Capacitance	$V_{CC} = 5\text{V}$, $V_{IN} = 2\text{V}$, $T_A = 25^\circ\text{C}$, 1 MHz		4		pF
C_O	Output Capacitance	$V_{CC} = 5\text{V}$, $V_O = 2\text{V}$, $T_A = 25^\circ\text{C}$, 1 MHz Output "Off"		6		pF

DM75S07/DM85S07 Switching Characteristicsover recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM75S07			DM85S07			Units	
				Min	Typ (Note 1)	Max	Min	Typ (Note 1)	Max		
t_{AA}	Access Times from Address		$C_L = 30 \text{ pF}$, $R_L = 280\Omega$ (Figure 4)		25	50		25	35	ns	
t_{CZH}	Output Enable Time to High Level	Access Times from Chip-Enable			12	25		12	17	ns	
t_{CZL}	Output Enable Time to Low Level				12	25		12	17	ns	
t_{WZH}	Output Enable Time to High Level	Sense Recovery Times from Read/Write			13	35		13	25	ns	
t_{WZL}	Output Enable Time to Low Level				13	35		13	25	ns	
t_{CHZ}	Output Disable Time from High Level	Disable Times from Chip-Enable		$C_L = 5 \text{ pF}$, $R_L = 280\Omega$ (Figure 4)		12	25		12	17	ns
t_{CLZ}	Output Disable Time from Low Level					12	25		12	17	ns
t_{WHZ}	Output Disable Time from High Level	Disable Times from Read/Write				15	35		15	25	ns
t_{WLZ}	Output Disable Time from Low Level				15	35		15	25	ns	
t_{WP}	Width of Write Enable Pulse (Read/Write Low)				25			25		ns	
t_{ASW}	Set-Up Time (Figure 1)	Address to Read/Write			0			0		ns	
t_{DSW}		Data to Read/Write			25			25		ns	
t_{CSW}		Chip-Enable to Read/Write			0			0		ns	
t_{AHW}	Hold Time (Figure 1)	Address from Read/Write		0			0		ns		
t_{DHW}		Data from Read/Write		0			0		ns		
t_{CHW}		Chip-Enable from Read/Write		0			0		ns		

DM75S07A/DM85S07A Switching Characteristicsover recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM75S07A			DM85S07A			Units
				Min	Typ (Note 1)	Max	Min	Typ (Note 1)	Max	
t_{AA}	Access Times from Address		$C_L = 30 \text{ pF}$, $R_L = 280\Omega$ (Figure 4)		20	30		20	25	ns
t_{CZH}	Output Enable Time to High Level	Access Times from Chip-Enable			12	25		12	17	ns
t_{CZL}	Output Enable Time to Low Level				12	25		12	17	ns
t_{WZH}	Output Enable Time to High Level	Sense Recovery Times from Read/Write			13	35		13	25	ns
t_{WZL}	Output Enable Time to Low Level				13	35		13	25	ns

DM75S07A/DM85S07A Switching Characteristics (Continued)

over recommended operating ranges of T_A and V_{CC} unless otherwise noted

DM75S06/DM85S06, DM75S07/DM85S07, DM75S07A/DM85S07A

Symbol	Parameter		Conditions	DM75S07A			DM85S07A			Units	
				Min	Typ (Note 1)	Max	Min	Typ (Note 1)	Max		
t_{CHZ}	Output Disable Time from High Level	Disable Times from Chip-Enable	$C_L = 5 \text{ pF}$, $R_L = 280\Omega$ (Figure 4)		12	25		12	17	ns	
t_{CLZ}	Output Disable Time from Low Level				12	25		12	17	ns	
t_{WHZ}	Output Disable Time from High Level			Disable Times from Read/Write		15	35		15	25	ns
t_{WLZ}	Output Disable Time from Low Level					15	35		15	25	ns
t_{WP}	Width of Write Enable Pulse (Read/Write Low)			25		20			ns		
t_{ASW}	Set-Up Time (Figure 1)	Address to Read/Write		0		0			ns		
t_{DSW}		Data to Read/Write		25		20			ns		
t_{CSW}		Chip-Enable to Read/Write		0		0			ns		
t_{AHW}		Hold Time (Figure 1)	Address from Read/Write		0		0			ns	
t_{DHW}	Data from Read/Write			0		0			ns		
t_{CHW}	Chip-Enable from Read/Write			0		0			ns		

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to $+125^\circ\text{C}$ temperature range for the DM75S07(A) and across the 0°C to $+70^\circ\text{C}$ range for the DM85S07(A). All typicals are given for $V_{CC} = 5.0\text{V}$ and $T_A = 25^\circ\text{C}$.

Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Note 5: I_{CC} is measured with all inputs grounded; and the outputs open.

DM75S07(A)/DM85S07(A) Switching Time Waveforms

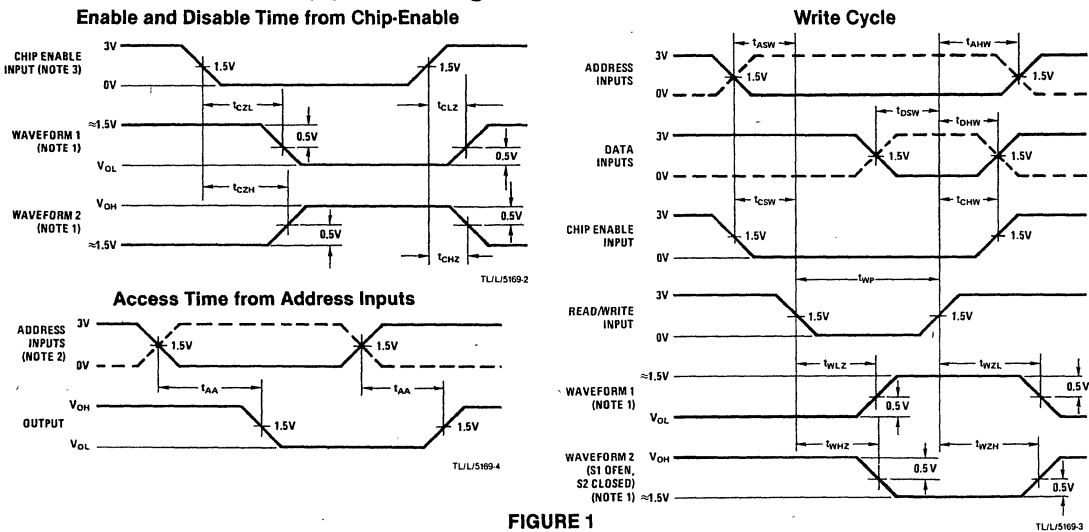


FIGURE 1

Note 1: Waveform 1 is for the output with internal conditions such that the output is low except when disabled. Waveform 2 is for the output with internal conditions such that the output is high except when disabled.

Note 2: When measuring delay times from address inputs, the chip-enable input is low and the read/write input is high.

Note 3: When measuring delay times from chip-enable input, the address inputs are steady-state and the read/write input is high.

Note 4: Input waveforms are supplied by pulse generators having the following characteristics: $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$, $\text{PRR} \leq 1 \text{ MHz}$ and $Z_{OUT} = 50\Omega$.

DM75S06/DM85S06 Switching Characteristics

over recommended operating ranges of T_A and V_{CC} unless otherwise noted

Symbol	Parameter		Conditions	DM75S06			DM85S06			Units
				Min	Typ (Note 1)	Max	Min	Typ (Note 1)	Max	
t_{AA}	Access Times from Address		$C_L = 30 \text{ pF}$, $R_{L1} = 300\Omega$, $R_{L2} = 600\Omega$ (Figure 4)		25	50		25	35	ns
t_{CHL}	Enable Time from Chip-Enable				12	25		12	17	ns
t_{WHL}	Enable Time from Read/Write	Sense Recovery Time from Read/Write			13	35		13	25	ns
t_{CLH}	Disable Time from Chip-Enable				12	25		12	20	ns
t_{WLH}	Disable Time from Read/Write				13	35		13	25	ns
t_{WP}	Width of Write Enable Pulse (Read/Write Low)				25			25		ns
t_{ASW}	Set-Up Time (Figure 2)	Address to Read/Write		0			0		ns	
t_{DSW}		Data to Read/Write		25			25		ns	
t_{CSW}		Chip-Enable to Read/Write		0			0		ns	
t_{AHW}		Hold Time (Figure 2)	Address from Read/Write		0			0		ns
t_{DHW}		Data from Read/Write		0			0		ns	
t_{CHW}		Chip-Enable from Read/Write		0			0		ns	

DM75S06/DM85S06 Switching Time Waveforms

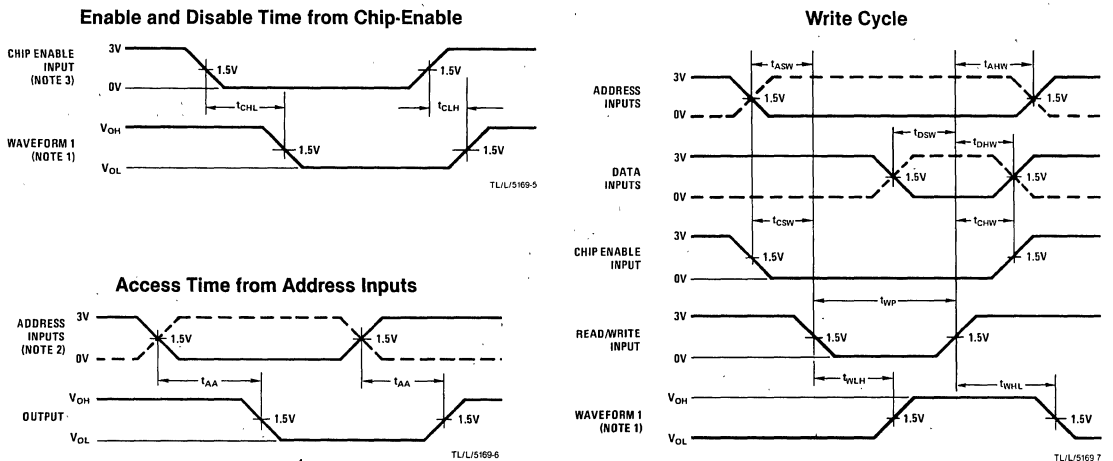


FIGURE 2

Note 1: Waveform 1 is for the output with internal conditions such that the output is low except when disabled.

Note 2: When measuring delay times from address inputs, the chip-enable input is low and the read/write input is high.

Note 3: When measuring delay times from chip-enable input, the address inputs are steady-state and the read/write input is high.

Note 4: Input waveforms are supplied by pulse generators having the following characteristics: $t_r \leq 2.5 \text{ ns}$, $t_f \leq 2.5 \text{ ns}$, $\text{PRR} \leq 1 \text{ MHz}$ and $Z_{OUT} = 50\Omega$.

Block Diagram

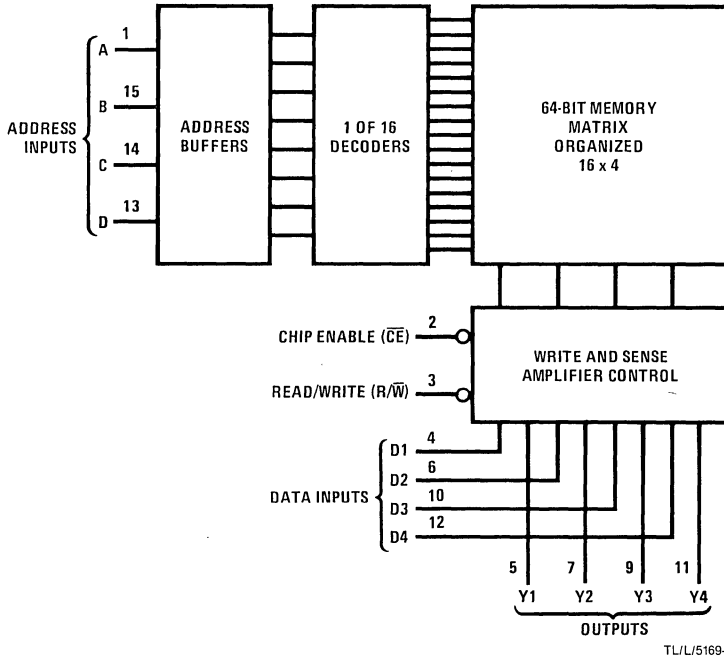
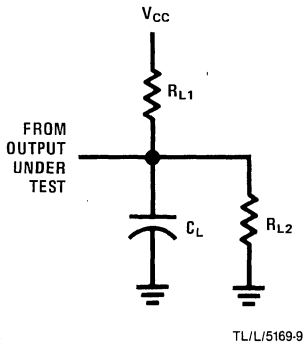


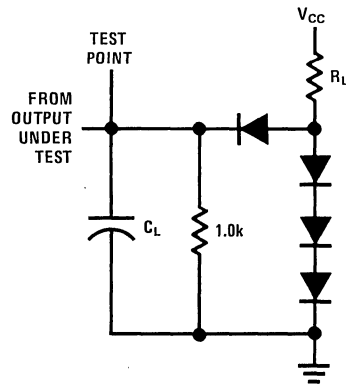
FIGURE 3

AC Test Circuits

DM75S06/DM85S06



DM75S07(A)/DM85S07(A)



C_L includes probe and jig capacitance.
All diodes are 1N3064.

FIGURE 4

DM75S06/DM85S06, DM75S07/DM85S07, DM75S07A/DM85S07A

DM77S401/DM87S401, DM77S402/DM87S402
First-In, First-Out (FiFo)
64 x 4, 64 x 5 Serial Memories

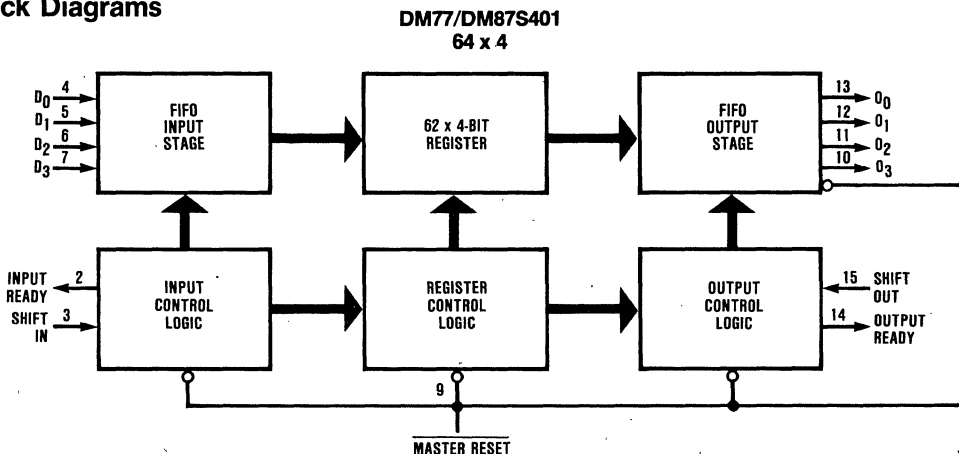
General Description

The DM77S401 is an expandable "fall-through" type high-speed First-in, First-out (FiFo) memory organized in 64-word by 4-bit, and 64-word by 5-bit structures respectively. A 10 MHz data rate allows usage in high-speed disc or tape controllers as well as PCM and communications buffer applications.

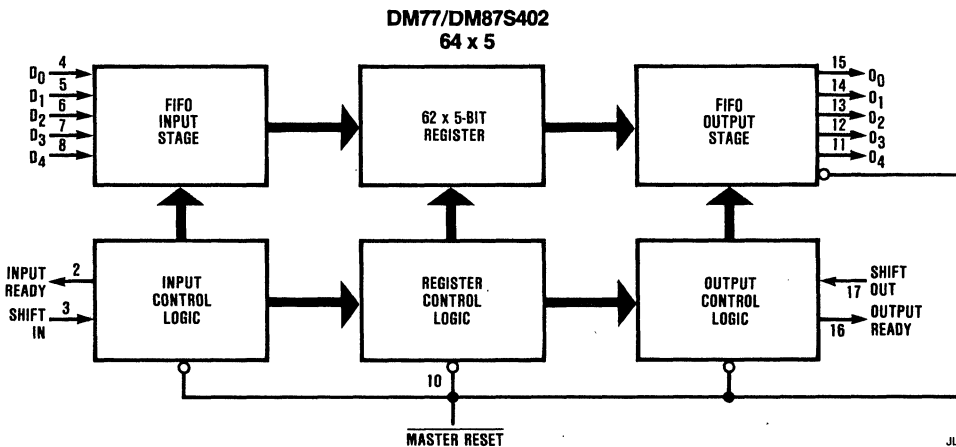
Features

- 10 MHz shift in, shift out
- TTL inputs and outputs
- Inputs and outputs are symmetrically placed on package
- Easily expandable word and bit dimensions
- Either synchronous or asynchronous operation
- Fairchild F3341 MOS FiFo pin compatible but many times faster!
- Choice of 4-bit or 5-bit data width

Block Diagrams



JL1000-1



JL1000-2

Absolute Maximum Ratings

Supply Voltage, V_{CC}	7 Volts
Input Voltage	7 Volts
Off-State Output Voltage	5.5 Volts
Storage Temperature	-65° to +150° C

Electrical Characteristics

 Over Operating Conditions DM77/DM87S401; DM77/DM87S402

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IL}	Low-Level Input Voltage				0.8	V
V_{IH}	High-Level Input Voltage		2			V
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}$, $I_I = -18\text{mA}$			-1.5	V
I_{IL}	Low-Level Input Current D_0 - D_4 , MR	$V_{CC} = \text{Max}$, $V_I = 0.45\text{V}$			-0.4	mA
I_{IH}	High-Level Input Current	$V_{CC} = \text{Max}$, $V_I = 2.4\text{V}$			50	μA
I_I	Maximum Input Current	$V_{CC} = \text{Max}$, $V_I = 5.5\text{V}$			1.0	mA
V_{OL}	Low-Level Output Voltage	$V_{CC} = \text{Min}$ $V_{IL} = 0.8\text{V}$ $V_{IH} = 2\text{V}$ $I_{OL} = 8\text{mA}$			0.5	V
V_{OH}	High-Level Output Voltage	$V_{CC} = \text{Min}$ $V_{IL} = 0.8\text{V}$ $V_{IH} = 2\text{V}$ $I_{OH} = -0.9\text{mA}$	2.4			V
I_{OS}	Output Short-Circuit Current (Note 1)	$V_{CC} = \text{Max}$, $V_O = 0\text{V}$	-20		-90	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max}$ Inputs Low, Outputs Open			190 160 210 180	mA

Operating Conditions

Symbol	Parameter	DM77S401/402			DM87S401/402			Units
		Min	Nom	Max	Min	Nom	Max	
V_{CC}	Supply Voltage	4.5	5	5.5	4.75	5	5.25	V
T_A	Operating Free-Air Temperature (Note 2)	-55		+125	0		+75	°C
t_{SIH}	Shift In HIGH Time	45	15		35	15		ns
t_{SIL}	Shift In LOW Time	45	22		35	22		ns
t_{IDS}	Input Data Setup	10	-9		0	-9		ns
t_{IDH}	Input Data Hold Time	55	30		45	30		ns
t_{SOH}	Shift Out HIGH Time	45	15		35	15		ns
t_{SOL}	Shift Out LOW Time	45	15		35	15		ns
t_{MRW}	Master Reset Pulse (Note 3)	40	15		35	15		ns
t_{MRS}	Master Reset to SI	45	15		35	15		ns

Note 1: Not more than one output should be shorted at a time and duration of the short-circuit should not exceed one second.

Note 2: Case temperature.

Note 3: Master reset clears all the cells to the empty state, and the data outputs to a LOW state.

Switching Characteristics Over Operating Conditions

Symbol	Parameter	DM77S401/402			DM87S401/402			Units
		Min	Typ	Max	Min	Typ	Max	
t_{IN}	Shift In Rate	7	16		10	16		MHz
t_{IRL}	Shift In to Input Ready LOW		30	60		30	45	ns
t_{IRH}^*	Shift In to Input Ready HIGH		33	60		33	45	ns
f_{OUT}	Shift Out Rate	7	16		10	16		MHz
t_{ORL}	Shift Out to Output Ready LOW		40	65		40	55	ns
t_{ORH}^{**}	Shift Out to Output Ready HIGH		45	70		45	60	ns
t_{OD}^{**}	Output Data Delay		38	65		38	55	ns
t_{PT}	Data Throughput or "Fall Through"		1.8	4		1.8	3	μ s
t_{MRORL}	Master Reset to OR LOW		30	65		30	60	ns
t_{MRIRH}	Master Reset to IR HIGH		30	65		30	60	ns
t_{IPH}	Input Ready Pulse HIGH	15	22		15	22		ns
t_{OPH}	Output Ready Pulse HIGH	15	22		15	22		ns

*This delay is dependent upon positive pulse width of SI input.

**These delays are dependent upon positive pulse width of SO input.

Functional Description

DATA INPUT

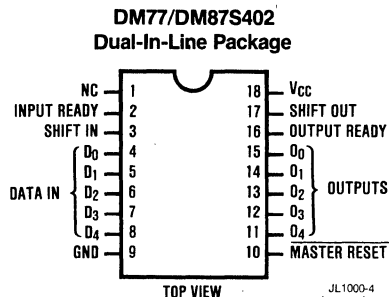
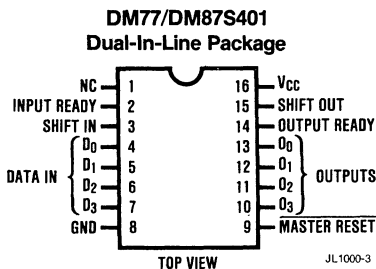
Data is entered in the FiFo on D_0 - D_3 (D_0 - D_4 on the 402) inputs. If the first location is ready to accept data, the Input Ready (IR) pin will be high. Data then present on the four input pins will be entered to the first location when the Shift In (SI) pin goes high. A high on the SI pin will cause the IR pin to go low. The old data will remain on the first location until SI is brought low again and IR goes low. If SI is brought low before IR goes low, data transfer will not take place until IR goes low. If the FiFo is not full (i.e., all locations contain data), IR will go high, indicating that the first location can accept more data from the four input pins. Simultaneously with IR going high, data will shift to the

second location and so forth until it either reaches the output stage or a full location. When the memory is full, IR will remain low and the FiFo will accept no more data.

DATA TRANSFER

Once data is entered into the second location, the transfer of any full location to the downstream adjacent empty location is automatically activated by an on-chip control. Thus data will stack up at the end of the FiFo while empty locations fill to the front. The time required for the first data to travel from input to output locations is called Data Throughput Time or t_{PT} .

Connection Diagrams



Order Number DM77S401J, DM87S401J,
DM77S402J, DM87S402J, DM77S401N,
DM87S401N, DM77S402N or DM87S402N
See NS Package J16A or N16A

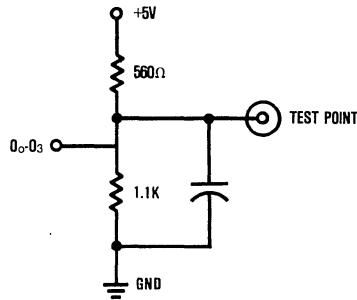
DATA OUTPUT

Data is output from Pins O_0 - O_3 (O_0 - O_4 on the 402). When data is shifted into the output stage, Output Ready (OR) goes high to indicate the presence of valid data. When the OR is high, data may be shifted out of O_0 - O_3 by pulling Shift Out (SO) high. A high signal on the SO pin will cause the OR pin to go low. When the SO pin is brought low again, and OR is low, any valid data at the next upstream stage is shifted to the output. Then all valid upstream data moves down one location. New valid data on the output stage will again

cause OR to go high unless the output stage is empty (all data shifted out), in which case OR stays low.

Input Ready (IR) and Output Ready (OR) may also be used as status signals since IR will stay low for at least t_{PT} if the FiFo is full and OR will stay low for at least t_{PT} if the FiFo is empty.

Standard Test Load



JL1000-5

DM77S401A/DM87S401A, DM77S402A/DM87S402A
First-In, First-Out (FiFo)
64 x 4, 64 x 5 Serial Memories

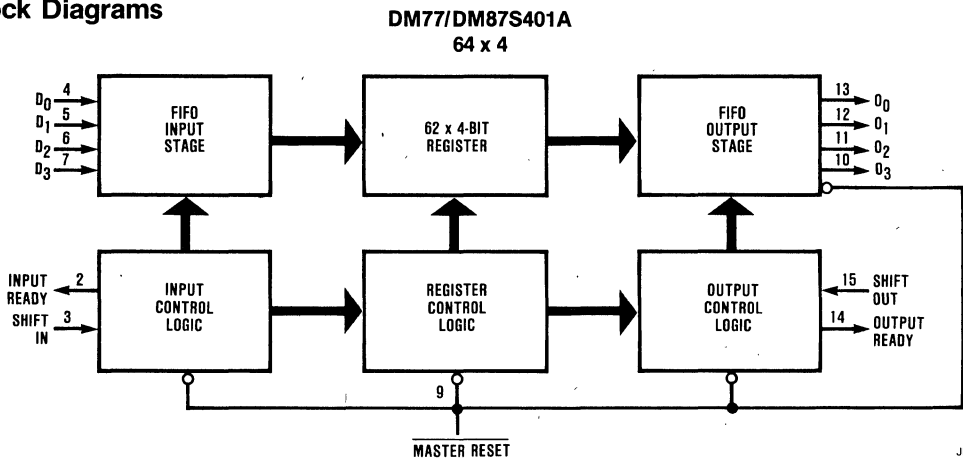
General Description

The DM77S401A is an expandable "fall-through" type high-speed First-in, First-out (FiFo) memory organized in 64-word by 4-bit, and 64-word by 5-bit structures respectively. A 15 MHz data rate allows usage in high-speed disc or tape controllers as well as PCM and communications buffer applications.

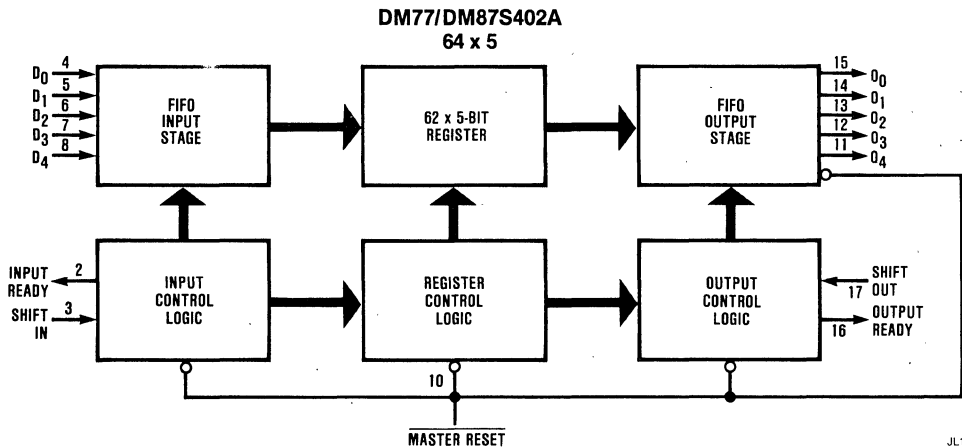
Features

- 15 MHz shift in, shift out
- TTL inputs and outputs
- Inputs and outputs are symmetrically placed on package
- Easily expandable word and bit dimensions
- Either synchronous or asynchronous operation
- Fairchild F3341 MOS FiFo pin compatible but many times faster!
- Choice of 4-bit or 5-bit data width

Block Diagrams



JL1000-1



JL1000-2

Absolute Maximum Ratings

Supply Voltage, V_{CC}	7 Volts
Input Voltage	7 Volts
Off-State Output Voltage	5.5 Volts
Storage Temperature	-65° to +150° C

Electrical Characteristics Over Operating Conditions DM77/DM87S401A, DM77/DM87S402A

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{IL}	Low-Level Input Voltage				0.8	V
V_{IH}	High-Level Input Voltage		2			V
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}, I_I = -18\text{mA}$			-1.5	V
I_{IL}	Low-Level D_0 - D_4 , MR Input Current	$V_{CC} = \text{Max}, V_I = 0.45\text{V}$			-0.4	mA
I_{IH}	High-Level Input Current	$V_{CC} = \text{Max}, V_I = 2.4\text{V}$			50	μA
I_I	Maximum Input Current	$V_{CC} = \text{Max}, V_I = 5.5\text{V}$			1.0	mA
V_{OL}	Low-Level Output Voltage	$V_{CC} = \text{Min}$ $V_{IL} = 0.8\text{V}$ $V_{IH} = 2\text{V}$ $I_{OL} = 8\text{mA}$			0.5	V
V_{OH}	High-Level Output Voltage	$V_{CC} = \text{Min}$ $V_{IL} = 0.8\text{V}$ $V_{IH} = 2\text{V}$ $I_{OH} = -0.9\text{mA}$	2.4			V
I_{OS}	Output Short-Circuit Current (Note 1)	$V_{CC} = \text{Max}, V_O = 0\text{V}$	-20		-90	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max}$ Inputs Low, Outputs Open			200 170 220 190	mA

Operating Conditions

Symbol	Parameter	DM77S401A/402A			DM87S401A/402A			Units
		Min	Nom	Max	Min	Nom	Max	
V_{CC}	Supply Voltage	4.5	5	5.5	4.75	5	5.25	V
T_A	Operating Free-Air Temperature (Note 2)	-55		+125	0		+75	$^{\circ}\text{C}$
t_{SIH}	Shift In HIGH Time	35	10		25	10		ns
t_{SIL}	Shift In LOW Time	40	21		33	21		ns
t_{IDS}	Input Data Setup	5	-9		0	-9		ns
t_{IDH}	Input Data Hold Time	45	24		40	24		ns
t_{SOH}	Shift Out HIGH Time	35	10		25	10		ns
t_{SOL}	Shift Out LOW Time	35	10		25	10		ns
t_{MRW}	Master Reset Pulse (Note 3)	30	10		20	10		ns
t_{MRS}	Master Reset to SI	45	10		20	10		ns

Note 1: Not more than one output should be shorted at a time and duration of the short-circuit should not exceed one second.

Note 2: Case temperature.

Note 3: Master reset clears all the cells to the empty state, and the data outputs to a LOW state.

Switching Characteristics Over Operating Conditions

Symbol	Parameter	DM77S401A/402A			DM87S401A/402A			Units
		Min	Typ	Max	Min	Typ	Max	
t_{IN}	Shift In Rate	10	20		15	20		MHz
t_{IRL}	Shift In to Input Ready LOW		25	50		25	40	ns
t_{IRH}^*	Shift In to Input Ready HIGH		30	50		30	42	ns
f_{OUT}	Shift Out Rate	10	20		15	20		MHz
t_{ORL}	Shift Out to Output Ready LOW		32	65		32	45	ns
t_{ORH}^{**}	Shift Out to Output Ready HIGH		34	65		34	50	ns
t_{OD}^{**}	Output Data Delay		32	60		32	50	ns
t_{PT}	Data Throughput or "Fall Through"		1.3	2.2		1.3	1.8	μ s
t_{MRORL}	Master Reset to OR LOW		26	65		26	60	ns
t_{MRIRH}	Master Reset to IR HIGH		25	65		25	60	ns
t_{IPH}	Input Ready Pulse HIGH	15	22		15	22		ns
t_{OPH}	Output Ready Pulse HIGH	15	22		15	22		ns

*This delay is dependent upon positive pulse width of SI input.

**These delays are dependent upon positive pulse width of SO input.

Functional Description

DATA INPUT

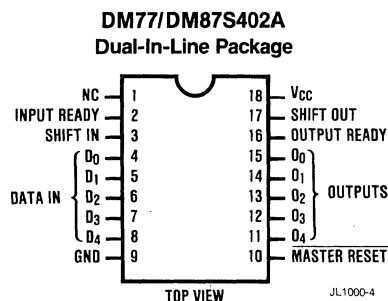
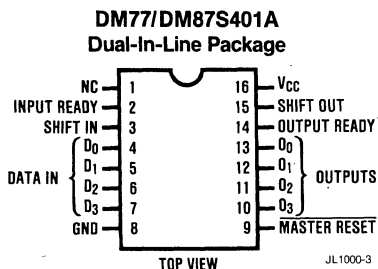
Data is entered in the FiFo on D_0 - D_3 (D_0 - D_4 on the 402) inputs. If the first location is ready to accept data, the Input Ready (IR) pin will be high. Data then present on the four input pins will be entered to the first location when the Shift In (SI) pin goes high. A high on the SI pin will cause the IR pin to go low. The old data will remain on the first location until SI is brought low again and IR goes low. If SI is brought low before IR goes low, data transfer will not take place until IR goes low. If the FiFo is not full (i.e., all locations contain data), IR will go high, indicating that the first location can accept more data from the four input pins. Simultaneously with IR going high, data will shift to the

second location and so forth until it either reaches the output stage or a full location. When the memory is full, IR will remain low and the FiFo will accept no more data.

DATA TRANSFER

Once data is entered into the second location, the transfer of any full location to the downstream adjacent empty location is automatically activated by an on-chip control. Thus data will stack up at the end of the FiFo while empty locations fill to the front. The time required for the first data to travel from input to output locations is called Data Throughput Time or t_{PT} .

Connection Diagrams



Order Number DM77S401AJ, DM87S401AJ,
DM77S402AJ, DM87S402AJ, DM77S401AN,
DM87S401AN, DM77S402AN or DM87S402AN
See NS Package J16A or N16A

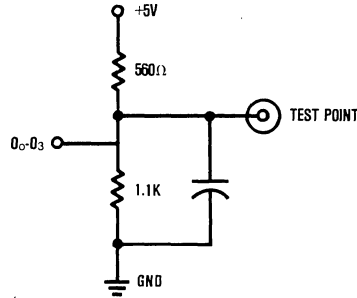
DATA OUTPUT

Data is output from Pins O_0 - O_3 (O_0 - O_4 on the 402). When data is shifted into the output stage, Output Ready (OR) goes high to indicate the presence of valid data. When the OR is high, data may be shifted out of O_0 - O_3 by pulling Shift Out (SO) high. A high signal on the SO pin will cause the OR pin to go low. When the SO pin is brought low again, and OR is low, any valid data at the next upstream stage is shifted to the output. Then all valid upstream data moves down one location. New valid data on the output stage will again

cause OR to go high unless the output stage is empty (all data shifted out), in which case OR stays low.

Input Ready (IR) and Output Ready (OR) may also be used as status signals since IR will stay low for at least t_{PT} if the FiFo is full and OR will stay low for at least t_{PT} if the FiFo is empty.

Standard Test Load



JL1000-5

DM75S68/DM85S68 16 x 4 Edge Triggered Registers

General Description

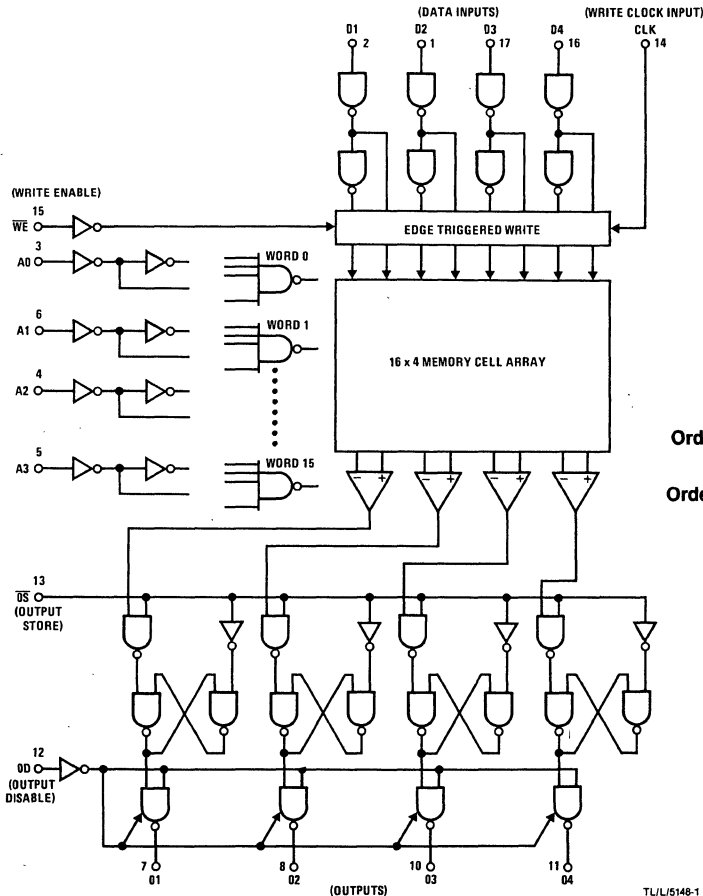
These Schottky memories are addressable "D" register files. Any of its 16 four-bit words may be asynchronously read or may be written into on the next clock transition. An input terminal is provided to enable or disable the synchronous writing of the input data into the location specified by the address terminals. An output disable terminal operates only as a TRI-STATE® output control terminal. The addressable register data may be latched at the outputs and retained as long as the output store terminal is held in a low state. This memory storage condition is independent of the state of the output disable terminal.

All input terminals are high impedance at all times, and all outputs have low impedance active drive logic states and the high impedance TRI-STATE condition.

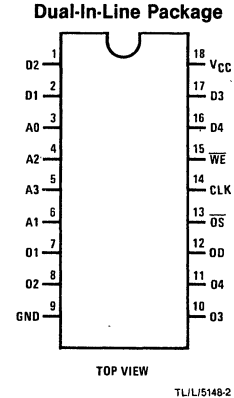
Features

- On-chip output register
- PNP inputs reduce input loading
- Edge triggered write
- High speed—30 ns typ
- All parameters guaranteed over temperature
- TRI-STATE output
- Schottky-clamped for high speed
- Optimized for register stack applications
- Typical power dissipation—350 mW

Logic and Block Diagram



Connection Diagram



Order Number DM75S68J or DM85S68J
See NS Package J18A

Order Number DM75S68N or DM85S68N
See NS Package N18A

TRI-STATE® is a registered trademark of National Semiconductor Corp.

Absolute Maximum Ratings (Note 1)

Supply Voltage	7.0V
Input Voltage	5.5V
Output Voltage	5.5V
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage, V_{CC}			
DM85S68	4.75	5.25	V
DM75S68	4.5	5.5	V
Temperature, T_A			
DM85S68	0	70	°C
DM75S68	-55	+125	°C

Electrical Characteristics

over recommended operating free-air temperature range unless otherwise noted (Notes 2 and 3)

Parameter		Conditions		Min	Typ	Max	Units
V_{IH}	High Level Input Voltage			2			V
V_{IL}	Low Level Input Voltage					0.8	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}$	$I_{OH} = -2.0 \text{ mA}$, DM75S68	2.4			V
			$I_{OH} = -5.2 \text{ mA}$, DM85S68	2.4			V
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}$, $I_{OL} = 16 \text{ mA}$	DM75S68			0.5	V
			DM85S68			0.45	V
I_{IH}	High Level Input Current	$V_{CC} = \text{Max}$, $V_{IH} = 2.4 \text{ V}$	Clock Input			50	μA
			All Others			25	μA
I_I	High Level Input Current at Maximum Voltage	$V_{CC} = \text{Max}$, $V_{IH} = 5.5 \text{ V}$				1.0	mA
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max}$, $V_{IL} = 0.5 \text{ V}$	Clock Input			-500	μA
			All Others			-250	μA
I_{OS}	Short Circuit Output Current (4)	$V_{CC} = \text{Max}$, $V_{OL} = 0 \text{ V}$		-20		-55	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max}$			70	100	mA
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min}$, $I_{IN} = -18 \text{ mA}$				-1.2	V
I_{OZ}	TRI-STATE Output Current	$V_{CC} = \text{Max}$	$V_O = 2.4 \text{ V}$			+40	μA
			$V_O = 0.5 \text{ V}$			-40	μA

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified min/max limits apply across the -55°C to +125°C temperature range for the DM75S68 and across the 0°C to +70°C range for the DM85S68. All typicals are given for $V_{CC} = 5.0 \text{ V}$ and $T_A = 25^\circ\text{C}$.

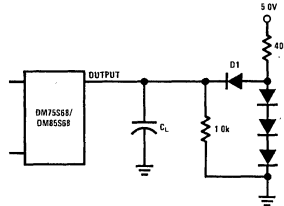
Note 3: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 4: Only one output at a time should be shorted.

Switching Characteristics over recommended operating range of T_A and V_{CC} unless otherwise noted

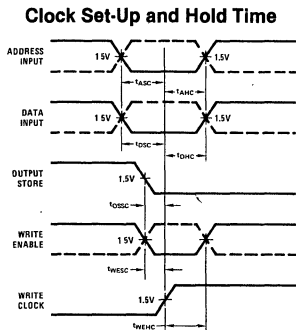
Parameter			DM75S68			DM85S68			Units
			Min	Typ	Max	Min	Typ	Max	
t_{ZH}	Output Enable to High Level		20	40		20	35	ns	
t_{ZL}	Output Enable to Low Level		14	30		14	24	ns	
t_{HZ}	Output Disable Time from High Level		10	18		10	15	ns	
t_{LZ}	Output Disable Time from Low Level		12	22		12	18	ns	
t_{AA}	Access Time	Address to Output	30	55		30	40	ns	
t_{OSA}		Output Store to Output	20	35		20	30	ns	
t_{CA}		Clock to Output	25	50		25	40	ns	
t_{ASC}	Set-Up Time	Address to Clock	25	5		15	5	ns	
t_{DSC}		Data to Clock	15	5		5	0	ns	
t_{ASOS}		Address to Output Store	40	15		30	15	ns	
t_{WESC}		Write Enable Set-Up Time	10	5		5	0	ns	
t_{OSSC}		Store Before Write	15	0		10	0	ns	
t_{AHC}		Hold Time	Address from Clock	15	5		10	5	ns
t_{DHC}	Data from Clock		20	5		15	5	ns	
t_{AHOS}	Address from Output Store		10	0		5	0	ns	
t_{WEHC}	Write Enable Hold Time		20	5		15	5	ns	

AC Test Circuit and Switching Time Waveforms



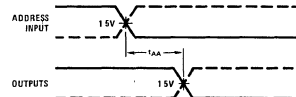
$C_L = 5.0$ pF for t_{HZ} , t_{LZ}
 $C_L = 30$ pF for all others
 C_L includes probe and jig capacitance
 All diodes are 1N3064

Write Cycle

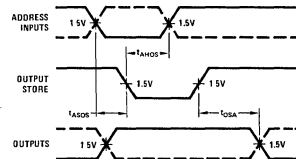


Read Cycle

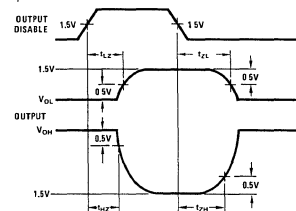
Address to Output Access Time



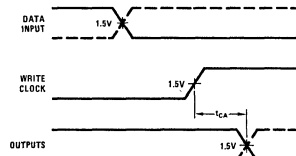
Output Store Access, Set-Up and Hold Time



Output Disable and Enable Time



Clock to Output Access



Note: Input waveforms supplied by pulse generator having the following characteristics: $V = 3.0V$, $t_R \leq 2.5$ ns, $PRR \leq 1.0$ MHz and $Z_{OUT} = 50M$.

IDM29705/29705A 16-Word by 4-Bit Two-Port RAM/Register File

General Description

The IDM29705 and IDM29705A are 16-word by 4-bit RAM/Register File chips housed in a standard 28-pin dual-in-line package. The IDM29705 and the IDM29705A feature TRI-STATE® outputs. These RAMs, which are fabricated using SCL® (Schottky ECL Technology) feature two separate output ports that enable any two 4-bit words to be read from these outputs simultaneously. Each output port contains a four-bit latch. A common Latch Enable (LE) input is used to control all eight latches. The device, which has two Write Enable (WE) inputs, is designed so that either Write Enable (WE_{1 or 2}) and Latch Enable (LE) inputs can be wired together to make the operation of the RAM appear edge-triggered.

The device, which has fully decoded A-address and B-address fields, can address any of the 16 memory words for the A-output port and, simultaneously, select any of the 16 words for presentation at the B-output port. Incoming data is written into the four-bit RAM word selected by the B-address. The D inputs are used to load the new data into the device.

Several of these devices can be cascaded to increase the total number of memory words in the system. When $\overline{OE-A}$ is high, the A-output port is in the high-impedance mode. $\overline{OE-B}$, when high, forces the B-output port to the high-impedance state.

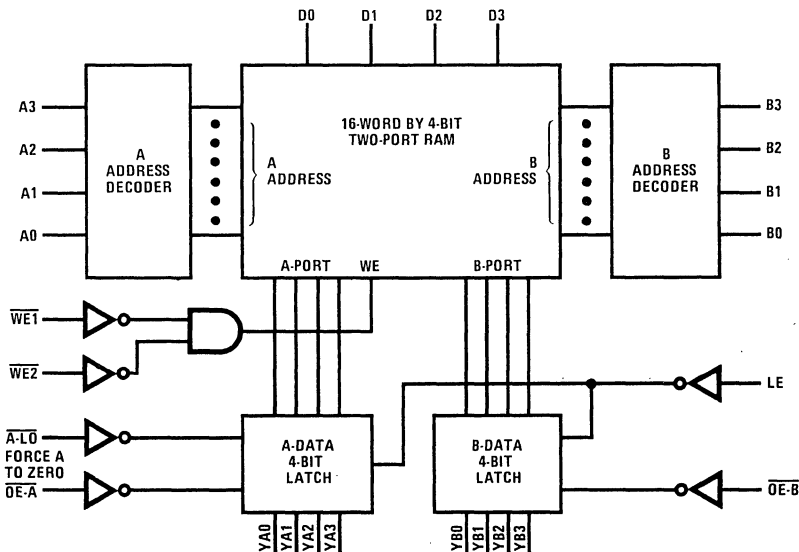
TRI-STATE® and SCL® are registered trademarks of National Semiconductor Corp.

The writing of new data into the RAM is controlled by the Write Enable inputs. With both Write Enable inputs low, data is written into the word selected by the B-address field. The memory outputs follow the data inputs during writing if the Latch Enable (LE) is high. With either Write Enable high, no data is written into the RAM.

Features and Benefits

- 16-Word by 4-Bit, 2-Port RAM/Register Files
- Two Output Ports, Each with Separate Output Control
- 4-Bit Latches on Each Output Port
- Non-Inverted Data Output with Respect to Data Input
- Output Enable and Write Enable Inputs Provide Ease in Cascading
- SCL Technology (Schottky ECL) Provides ECL Speeds While Keeping Low Power Schottky Input/Output Voltage and Power Consumption Compatibility
- 100% Reliability Testing in Compliance with MIL-STD-883

IDM29705/29705A Block Diagram



TLL5192

Absolute Maximum Ratings

Storage Temperature	- 65°C to + 150°C
Temperature (Ambient) Under Bias	- 55°C to + 125°C
Supply Voltage to Ground Potential	- 0.5V to + 6.3V
DC Voltage Applied to Outputs for High Output State	- 0.5V to + V _{CC} max
DC Input Voltage	- 0.5V to + 5.5V
DC Output Current, into Outputs	30mA
DC Input Current	- 30mA to + 5.0mA

Operating Range

P/N	Ambient	V _{CC}
	Temperature	
IDM29705JC	0°C to +70°C	4.75V to 5.25V
IDM29705JM, JM/883	-55°C to +125°C	4.50V to 5.50V
IDM29705AJC, NC	0°C to +70°C	4.75V to 5.25V
IDM29705AJM, JM/883	-55°C to +125°C	4.50V to 5.50V

Standard Screening (conforms to MIL-STD-883 for Class C parts)

Step	MIL-STD-883 Method	Conditions	Level	
			DC, PC	DM, FM
Pre-Seal Visual Inspection	2010	B	100%	100%
Stabilization Bake	1008	C: 24-hour 150°C	100%	100%
Temperature Cycle	1010	C: - 65°C to + 150°C 10 cycles	100%	100%
Centrifuge	2001	B: 10,000 G	100%	100%
Fine Leak	1014	A: 5x10 ⁻⁸ atm-cc/cm ³	100%	100%
Gross Leak	1014	C2: Fluorocarbon	100%	100%
Electrical Test Subgroups 1 and 7 and 9	5004	See below for definitions of subgroups	100%	100%
Insert Additional Screening Here for Class B Parts				
Group A Sample Tests Subgroup 1 Subgroup 2 Subgroup 3 Subgroup 7 Subgroup 8 Subgroup 9	5005	See below for definitions of subgroups	LTPD = 5 LTPD = 7 LTPD = 7 LTPD = 7 LTPD = 7 LTPD = 7	LTPD = 5 LTPD = 7 LTPD = 7 LTPD = 5 LTPD = 7 LTPD = 5

Additional Screening for Class B Parts

Step	MIL-STD-883 Method	Conditions	Level
			DMB, FMB
Burn-In	1015	D: 125°C, 160 hours min	100%
Electrical Test Subgroup 1 Subgroup 2 Subgroup 3 Subgroup 7 Subgroup 9	5004		100% 100% 100% 100% 100%
Return to Group A Tests in Standard Screening			

Group A Subgroups

(as defined in MIL-STD-883, method 5005)

Subgroup	Parameter	Temperature
1	DC	25°C
2	DC	Maximum rated temperature
3	DC	Minimum rated temperature
7	Function	25°C
8	Function	Maximum and minimum rated temperature
9	Switching	25°C
10	Switching	Maximum rated temperature
11	Switching	Minimum rated temperature

Electrical Characteristics (over operating temperature range, unless otherwise noted)

Symbol	Parameter	Test Conditions (Note 1)		Min.	Typ (Note 2)	Max.	Units		
V _{OH}	Output HIGH Voltage (IDM29705 only)	V _{CC} = min V _{IN} = V _{IH} or V _{IL}	Mil, I _{OH} = -2.0mA	2.4			Volts		
			Com'l, I _{OH} = -4.0mA	2.4					
V _{OL}	Output LOW Voltage	V _{CC} = min V _{IN} = V _{IH} or V _{IL}	I _{OL} = 4.0mA			0.4	Volts		
			I _{OL} = 8.0mA			0.45			
			I _{OL} = 12mA			0.5			
			I _{OL} = 16mA (Note 4)			0.5			
V _{IH}	Input HIGH Level	Guaranteed input logical HIGH voltage for all inputs		2.0			Volts		
V _{IL}	Input LOW Level	Guaranteed input logical LOW voltage for all inputs				0.8	Volts		
V _I	Input Clamp Voltage	V _{CC} = min, I _{IN} = -18mA				-1.5	Volts		
I _{IL}	Input LOW Current	V _{CC} = max, V _{IN} = 0.4V	A _i , B _i			-0.25	mA		
			Others			-0.36			
I _{IH}	Input HIGH Current	V _{CC} = max, V _{IN} = 2.7V				20	μA		
I _I	Input HIGH Current	V _{CC} = max, V _{IN} = 5.5V				0.1	mA		
I _{oz}	Off State (High Impedance) Output Current	V _{CC} = max V _{IN} = V _{IH} or V _{IL}	V _o = 2.7V			20	μA		
			V _o = 0.4V			-20			
I _{sc}	Output Short Circuit Current (Note 3)	V _{CC} = max	29705A	-30		-85	mA		
			29705	-25		-85			
I _{CC}	Power Supply Current	V _{CC} = max			120	175	mA		
			AJC	V _{CC} = 5.25V, T = 70 °C				155	mA
			AJM	V _{CC} = 5.5V, T = 125 °C				145	

Note 1: For conditions shown as Min. or Max., use the appropriate value specified under Electrical Characteristics for the applicable device type.
Note 2: Typical limits are at V_{CC} = 5.0V, 25°C ambient and maximum loading.
Note 3: Not more than one output should be shorted at a time. Duration of the short circuit test should not exceed one second.
Note 4: 29705A commercial temperature range only.

Switching Characteristics (Input Levels = 0V and 3.0V, Transitions measured at 1.5V)
Combinational Delays (in nanoseconds) (C_L = 50 pF)

Parameters	From	To	Conditions	Comm'l		Mil	
				Max. (Note 1)		Max. (Note 2)	
				705	705A	705	705A
Access Time	A Address Stable	YA Stable	LE = HIGH	40	30	55	35
	B Address Stable	YB Stable		40	30	55	35
	Both WE LOW	YA = D	LE = HIGH, A = B	45	45	48	45
		YB = D	LE = HIGH	45	45	48	45
Turn-On Time	OE-A or OE-B LOW			25	20	25	25
Turn-Off Time	OE-A or OE-B HIGH	YA or YB Off	C _L = 5pF (Note 3)	20	20	20	20
Reset Time	A-LO LOW	YA LOW		20	20	30	25
Enable Time	LE HIGH	YA and YB Stable		25	20	25	25
	Data In	YA or YB = D	LE = HIGH, WE both LOW, A = B	45	45	45	45

Switching Characteristics (Cont'd)

Minimum Setup and Hold Times (in nanoseconds)

Parameters	From	To	Conditions	Comm'l		Mil	
				Max. (Note 1)		Max. (Note 2)	
				705	705A	705	705A
Data Setup Time	D Stable	Either WE HIGH		20	15	25	20
Data Hold Time	Either WE HIGH	D Changing		0	0	0	0
Address Setup Time	B Stable	Both WE LOW		3	0	5	3
Address Hold Time	Either WE HIGH	B Changing		0	0	0	0
Latch Close Before Write Begins	LE LOW	WE ₁ LOW	WE ₂ LOW	0	0	0	0
	LE LOW	WE ₂ LOW	WE ₁ LOW	0	0	0	0
Address Setup Before Latch Closes	A or B Stable	LE LOW		20	15	40	20

Minimum Pulse Widths (in nanoseconds)

Parameters	From	To	Conditions	Comm'l		Mil	
				Max. (Note 1)		Max. (Note 2)	
				705	705A	705	705A
Write Pulse Width	WE ₁	HIGH-LOW-HIGH	WE ₂ LOW	25	20	25	20
	WE ₂	HIGH-LOW-HIGH	WE ₁ LOW	20	20	20	20
A Latch Reset Pulse	A-LO	HIGH-LOW-HIGH		20	15	20	15
Latch Data Capture	LE	LOW-HIGH-LOW	Address Stable	20	15	20	15

Note 1: T_A = 0°C to +70°C, V_{CC} = 5.0V ± 5%.

Note 2: -55°C to +125°C, V_{CC} = 5.0V ± 10%

Note 3: Measured from 1.5V at the input to 0.5V change in the output level.

Function Tables

Write Control

WE ₁	WE ₂	Function	RAM Outputs at Latch Inputs	
			A-Port	B-Port
L	L	Write D into B	A data (A ≠ B)	D input data
X	H	No write	A data	B data
H	X	No write	A data	B data

YA Read

Inputs			YA Output	Function
OE-A	A-LO	LE		
H	X	X	Z	High impedance
L	L	X	L	Force YA LOW
L	H	H	A-Port RAM data	Latches transparent
L	H	L	NC	Latches retain data

Function Tables (continued)

YB Read

Inputs		YB Output	Function
OE-B	LE		
H	X	Z	High impedance
L	H	B-Port RAM data	Latches transparent
L	L	NC	Latches retain data

H = HIGH Z = High impedance
 L = LOW NC = No change
 X = Don't care

Pinout Descriptions of the IDM29705/29705A

D₃-D₀: Through these inputs new data can be written in the location specified by the B-address inputs.

A₃-A₀: The 4-bit address presented at the A inputs selects one of the 16 memory words for presentation at the A-data latch outputs.

B₃-B₀: The 4-bit address presented at the B inputs selects one of the 16 memory words for presentation at the B-data latch outputs. This address also selects the location into which data is written.

YA₃-YA₀: The four A-data latch outputs.

YB₃-YB₀: The four B-data latch outputs.

WE₁, WE₂: Write enable inputs. When both are low, enables data to be written into the RAM location selected by the B-address field. When either Write Enable input is high, no data can be written into memory.

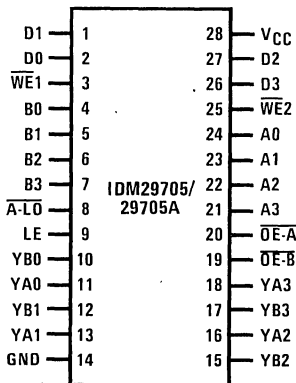
OE-A: A-port output enable. When low, data in the A-data latch is present at the YA_i outputs. When high, the YA_i outputs are in the high-impedance mode.

OE-B: B-port output enable. When low, data in the B-data latch is presented at the YB_i outputs. When high, the YB_i outputs are in the high-impedance mode.

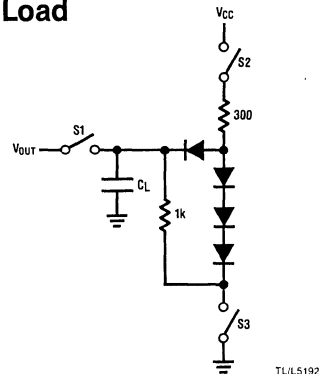
LE: Latch enable. The LE input acts as control for both the RAM-A and RAM-B output ports. When high the latches are transparent and data from the RAM, as selected by the A and B address inputs, is presented at the outputs. When low, the latches retain the last data read from the RAM regardless of the current A and B address inputs.

A-LO: Force A to zero. This input operates to force the A-port latch outputs low independent of the LE input or A address inputs. The A-output bus can be forced low using this control input. With A-LO high, the A latches operate in their normal manner. Once forced low, the A latches remain low independent of the A-LO input if the Latch Enable (LE) is low.

IDM29705/29705A Connection Diagram and Test Load



TUL5192



Note 1: C_L = 50 pF includes scope probe, wiring and stray capacitances without device in test fixture.

Note 2: S₁, S₂, S₃ are closed during function tests and all AC tests except output enable tests.

Note 3: S₁ and S₃ are closed while S₂ is open for tp_{ZH} test. S₁ and S₂ are closed while S₃ is open for tp_{ZL} test.

Note 4: C_L = 5 pF for output disable tests.



DM10414, DM10414A 256 x 1 ECL Random Access Memory

General Description

The DM10414, DM10414A is a 256-word by 1-bit ECL random access memory. The fully static memory is designed with active low chip selects and separate I/O pins. The 8 address bits (A0 through A7) are fully decoded on the chip. Applications such as scratch pad, cache, and buffer memories are ideal for this high speed RAM.

An unterminated emitter-follower output is provided to allow the outputs to be wire-ORed. Separate Data In and non-inverted Data Out pins are provided. These RAMs are compatible with compensated and uncompensated 10k ECL families.

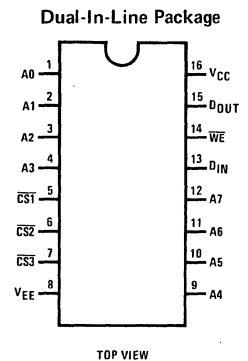
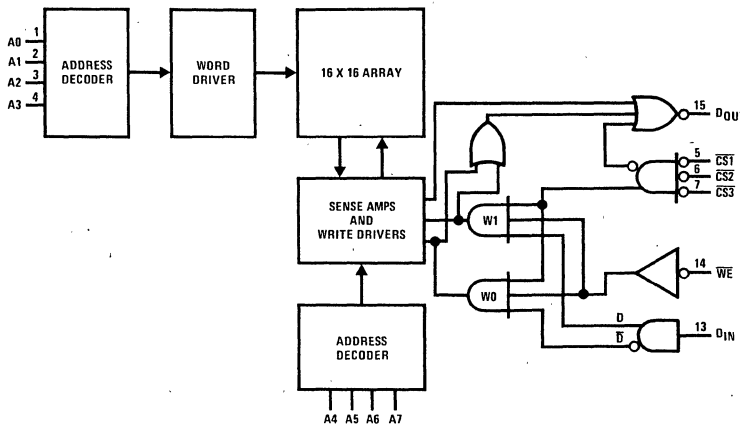
Features

- Fully compatible with standard and voltage compensated 10k series ECL
- Temperature range 0°C to +75°C
- Unterminated emitter-follower output for wire-ORing
- Power dissipation decreases with increasing temperature
- Typical address access

DM10414	10 ns
DM10414A	7 ns
- Typical chip select access

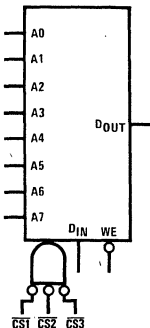
DM10414	4 ns
DM10414A	3 ns

Block and Connection Diagrams



Order Number DM10414J
or DM10414AJ
See NS Package J16A

Logic Symbol



Pin Names

- A0–A7 Address Inputs
- D_{IN} Data Input
- D_{OUT} Data Output
- CS1, CS2, CS3 Chip Select Inputs
- WE Write Enable

Truth Table

CS	WE	D _{IN}	D _{OUT}	MODE
H	X	X	L	Not Selected
L	L	H	L	Write 1
L	L	L	L	Write 0
L	H	X	D _{OUT}	Read

L = low (–1.7V nominal)
H = high (–0.9V nominal)
X = don't care

Absolute Maximum Ratings

Temperature Under Bias (Ambient)	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
V _{EE} Relative to V _{CC}	-7.0V to +0.5V
Any Input Relative to V _{CC}	V _{EE} to +0.5V
Output Current (Output High)	-30 mA to +0.1 mA
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{EE})	-5.46	-4.94	V
Ambient Temperature (T _A)	0	+75	°C

DC Electrical Characteristics

V_{EE} = -5.2V, Output Load = 50Ω and 30 pF to -2.0V, T_A = 0°C to +75°C (Notes 1-4)

SYMBOL	PARAMETER	CONDITIONS	T _A	B LIMIT	A LIMIT	UNITS
V _{OH}	Output Voltage High	V _{IN} = V _{IHA} or V _{ILB}	0°C +25°C +75°C	-1000 -960 -900	-840 -810 -720	mV
V _{OL}	Output Voltage Low	V _{IN} = V _{IHA} or V _{ILB}	0°C +25°C +75°C	-1870 -1850 -1830	-1665 -1650 -1625	mV
V _{OH} C	Output Voltage High	V _{IN} = V _{IHB} or V _{IILA} Performed on one input at a time	0°C +25°C +75°C	-1020 -980 -920		mV
V _{OL} C	Output Voltage Low	V _{IN} = V _{IHB} or V _{IILA} Performed on one input at a time	0°C +25°C +75°C		-1645 -1630 -1605	mV
V _{IH}	Input Voltage High	Guaranteed Input Voltage High for All Inputs	0°C +25°C +75°C	-1145 -1105 -1045	-840 -810 -720	mV
V _{IL}	Input Voltage Low	Guaranteed Input Voltage Low for All Inputs	0°C +25°C +75°C	-1870 -1850 -1830	-1490 -1475 -1450	mV
I _{IH}	Input Current High	V _{IN} = V _{IHA} Performed on one input at a time	0°C to +75°C		220	μA
I _{IL}	Input Current Low, $\overline{\text{CS}}$ All Others	V _{IN} = V _{ILB} Performed on one input at a time	0°C to +75°C	0.5 -50	170	μA
I _{EE}	Power Supply Current (Pin 8) (Note 5)	All Inputs and Outputs Open	0°C to +75°C		-150	mA

Note 1: Conditions for testing not shown in the tables are chosen to guarantee operation under "worst case" conditions.

Note 2: The specified limits represent the "worst case" value for the parameter. Since these "worst case" values normally occur at the temperature extremes, additional noise immunity and guard banding can be achieved by decreasing the allowable system operating ranges.

Note 3: Guaranteed with transverse air flow exceeding 400 linear F.P.M. and 2-minute warm-up period. Typical resistance values of the package are: θ_{JA} , (Junction to Ambient) = 90°C/W (still air); θ_{JA} (Junction to Ambient) = 50°C/W (at 400 F.P.M. air flow); θ_{JC} (Junction to Case) = 25°C/W.

Note 4: "A" indicates the most positive value, "B" indicates the most negative value.

Note 5: Typical values at V_{EE} = -5.2V; T_A = 0°C, I_{EE} = -105 mA; T_A = 75°C, I_{EE} = -90 mA.

Functional Description

Addressing the DM10414, DM10414A is achieved by means of the 8 address lines A0–A7. Each of the 2^8 one-zero combinations of the address lines corresponds to a bit location in the memory. The active low Chip Selects together with the unterminated emitter-follower output allows for wire-ORing. A 50Ω resistor to $-2V$ (or an equivalent network) is required to provide a low at the output when the device is off. This termination is required for both single device or wire-ORed operation.

The device is selected with \overline{CS} low and deselected with \overline{CS} high. The operating mode is controlled by the active low Write Enable (WE). WE low causes the data at the Data Input (D_{IN}) to be stored at the selected address. WE low also causes the output to be disabled (low due to the 50Ω pull-down resistor). WE high causes the data stored at the selected address to be present at the Data Out (D_{OUT}) pin.

AC Electrical Characteristics

$V_{EE} = -5.2V \pm 5\%$, Output Load = 50Ω , 30 pF to $-2.0V$, $T_A = 0^\circ C$ to $75^\circ C$, 400 LFM

SYMBOL	PARAMETER	CONDITIONS	DM10414A			DM10414			UNITS
			MIN	TYP (NOTE 6)	MAX	MIN	TYP (NOTE 6)	MAX	
READ MODE									
t _{ACS}	Chip Select Access Time	Measured Between 50% Points (Note 7)		3	5		4	7	ns
t _{RCS}	Chip Select Recovery Time			3	5		4	7	ns
t _{AA}	Address Access Time			7	10		10	15	ns
WRITE MODE									
t _W	Write Pulse Width (to Guarantee Writing)	Measured Between 50% Points	6	3.5		8	5		ns
t _{WSD}	Data Set-Up Time Prior to Write		2	0		2	0		ns
t _{WHD}	Data Hold Time After Write		2	0		2	0		ns
t _{WSA}	Address Set-Up Time Prior to Write		3	0		4	0		ns
t _{WHA}	Address Hold Time After Write		2	0		3	1		ns
t _{WSCS}	Chip Select Set-Up Time Prior to Write		2	0		2	0		ns
t _{WHCS}	Chip Select Hold Time After Write		2	0		2	0		ns
t _{WS}	Write Disable Time			3	5		4	7	ns
t _{WR}	Write Recovery Time			3	5		4	7	ns
RISE TIME AND FALL TIME									
t _r	Output Rise Time	Measured Between 50% Points		3			4		ns
t _f	Output Fall Time			3			4		ns

Capacitance

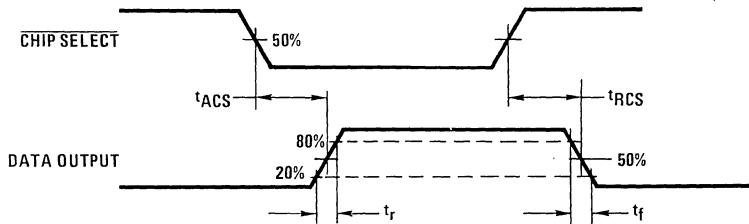
SYMBOL	PARAMETER	CONDITIONS	DM10414A			DM10414			UNITS
			MIN	TYP (NOTE 6)	MAX	MIN	TYP (NOTE 6)	MAX	
C _{IN}	Input Pin Capacitance	Measure With a Pulse Technique		4	5		4	5	pF
C _{OUT}	Output Pin Capacitance				7	8		7	8

Note 6: Typical values are at $V_{EE} = -5.2V$, $T_A = 25^\circ C$ and maximum loading.

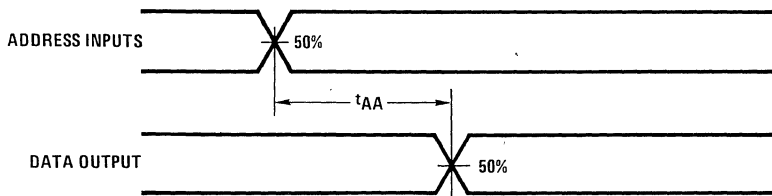
Note 7: The maximum address access time is guaranteed to be the worst case bit in the memory using a pseudorandom testing pattern.

Switching Time Waveforms

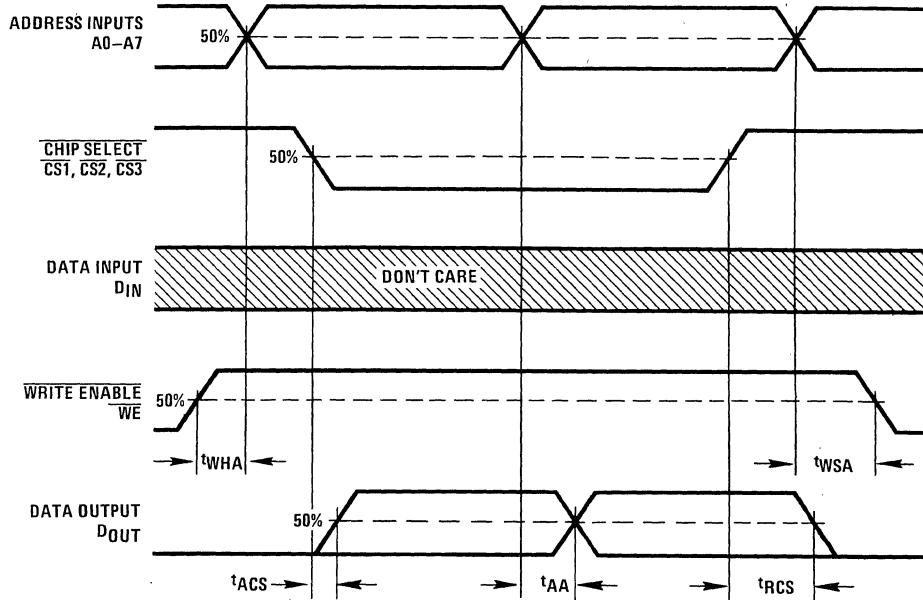
Chip Select Access Time



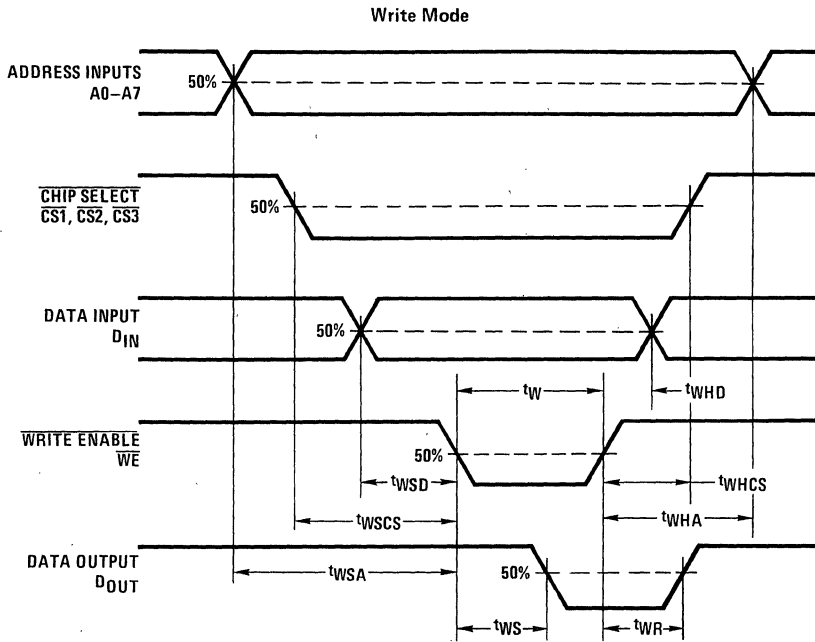
Address Access Time



Read Mode

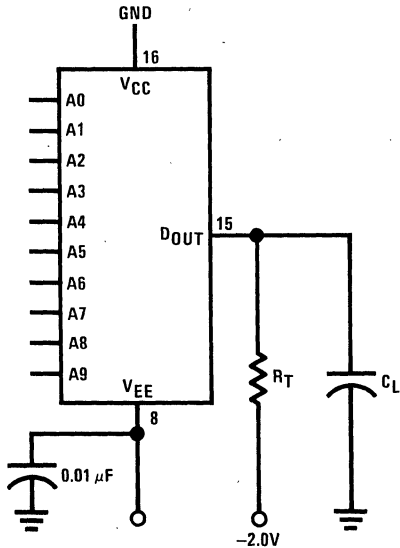


Switching Time Waveforms (Continued)

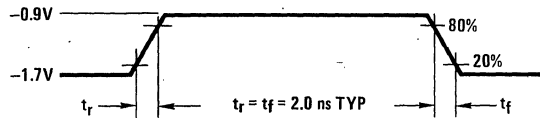


Test Conditions

Loading Conditions



Input Levels



All timing measurements referenced to 50% of input levels
 $C_L = 30 \text{ pF}$ including jig and stray capacitance
 $R_T = 50 \Omega$

DM10415, DM10415A 1024 × 1 ECL Random Access Memory

General Description

The DM10415, DM10415A is a 1024-word by 1-bit ECL random access memory. This fully static memory is designed with an active low chip select and separate I/O pins. The 10 address bits (A0 through A9) are fully decoded on the chip. Applications such as scratch pad, cache, and buffer memories are ideal for this high speed RAM.

An unterminated emitter-follower output is provided to allow the outputs to be wire-ORed. Separate Data In and non-inverted Data Out pins are provided. These RAMs are compatible with compensated and uncompensated 10k ECL families.

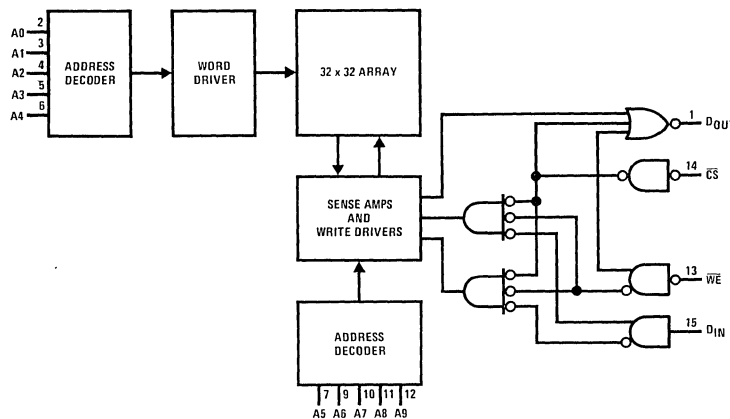
Features

- Fully compatible with standard and voltage compensated 10k series ECL
- Temperature range 0°C to +75°C
- Unterminated emitter-follower output for wire-ORing
- Power dissipation decreases with increasing temperature
- Typical address access

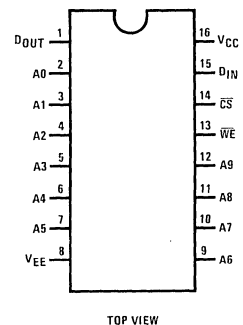
DM10415	25 ns
DM10415A	12 ns
- Typical chip select access

DM10415	7 ns
DM10415A	4 ns

Block and Connection Diagrams

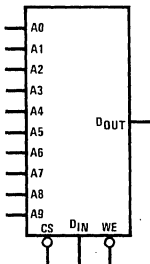


Dual-In-Line Package



Order Number DM10415J
or DM10415AJ
See NS Package J16A

Logic Symbol



Pin Names

- A0–A9 Address Inputs
- DIN Data Input
- DOUT Data Output
- CS Chip Select
- WE Write Enable

Truth Table

CS	WE	DIN	DOUT	MODE
H	X	X	L	Not Selected
L	L	H	L	Write 1
L	L	L	L	Write 0
L	H	X	DOUT	Read

L = low (–1.7V nominal)
H = high (–0.9V nominal)
X = don't care

Absolute Maximum Ratings

Temperature Under Bias (Ambient)	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
V _{EE} Relative to V _{CC}	-7.0V to +0.5V
Any Input Relative to V _{CC}	V _{EE} to +0.5V
Output Current (Output High)	-30 mA to +0.1 mA
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	MIN	MAX	UNITS
Supply Voltage (V _{EE})	-5.46	-4.94	V
Ambient Temperature (T _A)	0	+75	°C

DC Electrical Characteristics

V_{EE} = -5.2V, Output Load = 50Ω and 30 pF to -2.0V, T_A = 0°C to +75°C (Notes 1 – 4)

SYMBOL	PARAMETER	CONDITIONS	T _A	B LIMIT	A LIMIT	UNITS
V _{OH}	Output Voltage High	V _{IN} = V _{IHA} or V _{ILB}	0°C +25°C +75°C	-1000 -960 -900	-840 -810 -720	mV
V _{OL}	Output Voltage Low	V _{IN} = V _{IHA} or V _{ILB}	0°C +25°C +75°C	-1870 -1850 -1830	-1665 -1650 -1625	mV
V _{OHc}	Output Voltage High	V _{IN} = V _{IHB} or V _{ILA}	0°C +25°C +75°C	-1020 -980 -920		mV
V _{OLc}	Output Voltage Low	V _{IN} = V _{IHB} or V _{ILA}	0°C +25°C +75°C		-1645 -1630 -1605	mV
V _{IH}	Input Voltage High	Guaranteed Input Voltage High for All Inputs	0°C +25°C +75°C	-1145 -1105 -1045	-840 -810 -720	mV
V _{IL}	Input Voltage Low	Guaranteed Input Voltage Low for All Inputs	0°C +25°C +75°C	-1870 -1850 -1830	-1490 -1475 -1450	mV
I _{IH}	Input Current High	V _{IN} = V _{IHA}	0°C to +75°C		220	μA
I _{IL}	Input Current Low, \overline{CS} All Others	V _{IN} = V _{ILB}	0°C to +75°C	0.5 -50	170	μA
I _{EE}	Power Supply Current (Pin 8) (Note 5)	All Inputs and Outputs Open	0°C to +75°C	-150		mA

Note 1: Conditions for testing not shown in the tables are chosen to guarantee operation under "worst case" conditions.

Note 2: The specified limits represent the "worst case" value for the parameter. Since these "worst case" values normally occur at the temperature extremes, additional noise immunity and guard banding can be achieved by decreasing the allowable system operating ranges.

Note 3: Guaranteed with transverse air flow exceeding 400 linear F.P.M. and 2-minute warm-up period. Typical resistance values of the package are: θ_{JA} , (Junction to Ambient) = 90°C/W (still air); θ_{JA} (Junction to Ambient) = 50°C/W (at 400 F.P.M. air flow); θ_{JC} (Junction to Case) = 25°C/W.

Note 4: "A" indicates the most positive value, "B" indicates the most negative value.

Note 5: Typical values at V_{EE} = -5.2V; T_A = 0°C, I_{EE} = -105 mA; T_A = 75°C, I_{EE} = -90 mA.

Functional Description

Addressing the DM10415/DM10415A is achieved by means of the 10 address lines A0–A9. Each of the 2¹⁰ one-zero combinations of the address lines corresponds to a bit location in the memory. The active low Chip Select (\overline{CS}) together with the unterminated emitter-follower output allows for memory array expansion to 2048 words without additional decoding. This emitter-follower output allows for wire-ORing. A 50 Ω resistor to -2V (or an equivalent network) is required to provide a low at the output when the device is off. This termination is required for both single device or wire-ORed operation.

The device is selected with \overline{CS} low and deselected with \overline{CS} high. The operating mode is controlled by the active low Write Enable (\overline{WE}). \overline{WE} low causes the data at the Data Input (D_{IN}) to be stored at the selected address. \overline{WE} low also causes the output to be disabled (low due to the 50 Ω pull-down resistor). \overline{WE} high causes the data stored at the selected address to be present at the Data Out (D_{OUT}) pin.

AC Electrical Characteristics

$V_{EE} = -5.2V, \pm 5\%$, Output Load = 50 $\Omega, 30$ pF to -2.0V, $T_A = 0^\circ C$ to $+75^\circ C, 400$ LFM

SYMBOL	PARAMETER	CONDITIONS	DM10415A			DM10415			UNITS
			MIN	TYP (NOTE 6)	MAX	MIN	TYP (NOTE 6)	MAX	
READ MODE									
tACS	Chip Select Access Time	Measured at 50% of Input to Valid Output (Note 7)		4	8		7	10	ns
tRCS	Chip Select Recovery Time			4	8		7	10	ns
tAA	Address Access Time			12	20		25	35	ns
WRITE MODE									
tW	Write Pulse Width (to Guarantee Writing) DM10415A DM10415	t _{WSA} = 8 ns t _{WSA} = 20 ns	12	10		25	20		ns
tWSD	Data Set-Up Time Prior to Write		4	0		5	0		ns
tWHD	Data Hold Time After Write		4	0		5	0		ns
tWSA	Address Set-Up Time Prior to Write DM10415A DM10415	t _W = 12 ns t _W = 25 ns	5	3		8	5		ns
tWHA	Address Hold Time After Write		3	0		4	1		ns
tWSCS	Chip Select Set-Up Time Prior to Write		4	0		5	0		ns
tWHCS	Chip Select Hold Time After Write		4	0		5	0		ns
tWS	Write Disable Time			4	10		7	10	ns
tWR	Write Recovery Time			4	10		7	10	ns
RISE TIME AND FALL TIME									
t _r	Output Rise Time	Measured Between 20% and 80% Points		5			5		ns
t _f	Output Fall Time			5			5		ns

Capacitance

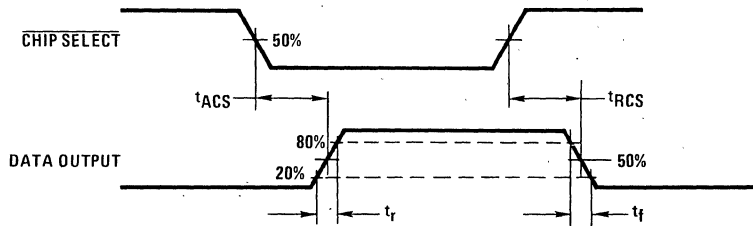
SYMBOL	PARAMETER	CONDITIONS	DM10415A			DM10415			UNITS
			MIN	TYP (NOTE 6)	MAX	MIN	TYP (NOTE 6)	MAX	
C _{IN}	Input Pin Capacitance	Measure With a Pulse Technique		4	5		4	5	pF
C _{OUT}	Output Pin Capacitance				7	8		7	8

Note 6: Typical values are at $V_{EE} = -5.2V, T_A = 25^\circ C$ and maximum loading.

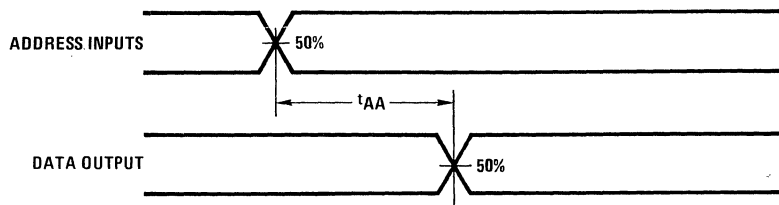
Note 7: The maximum address access time is guaranteed to be the worst case bit in the memory using a pseudorandom testing pattern.

Switching Time Waveforms

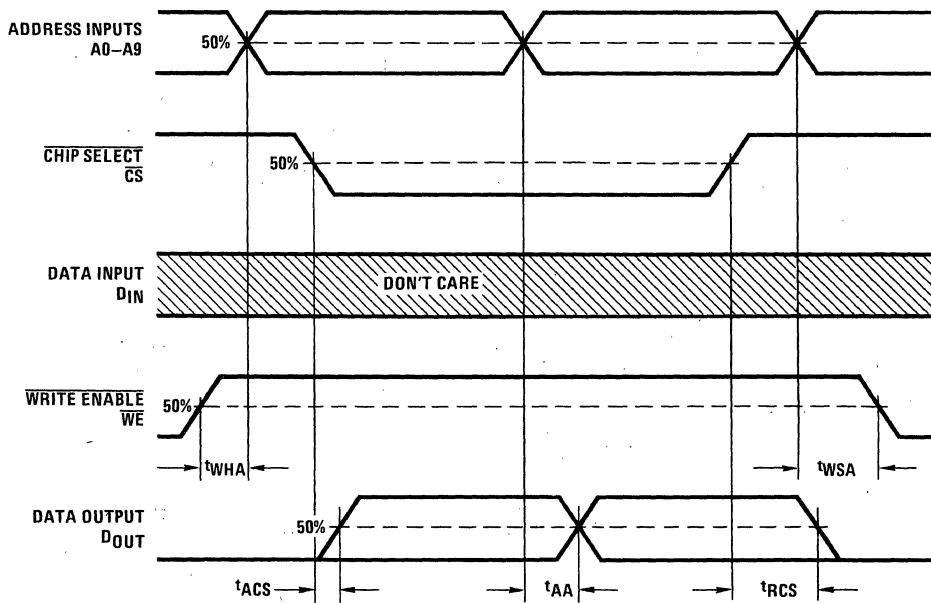
Chip Select Access Time



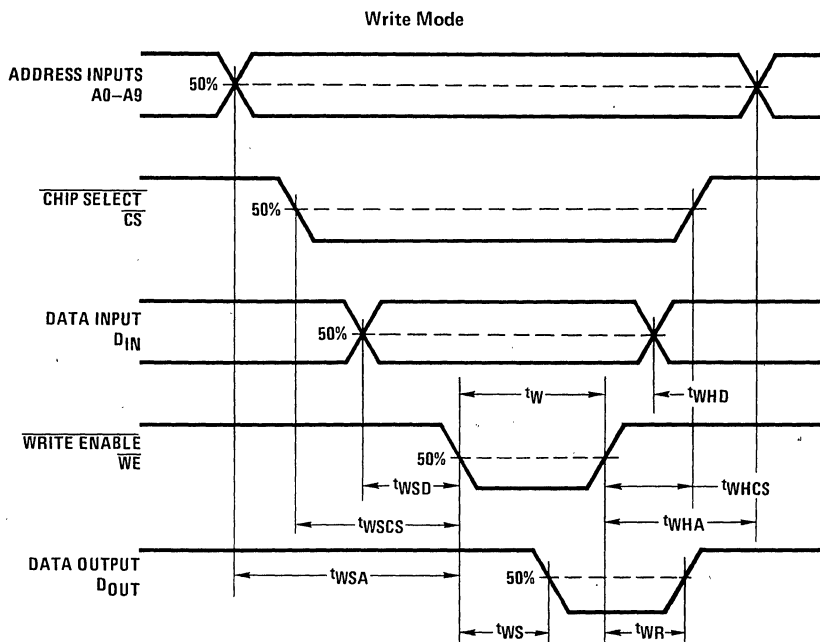
Address Access Time



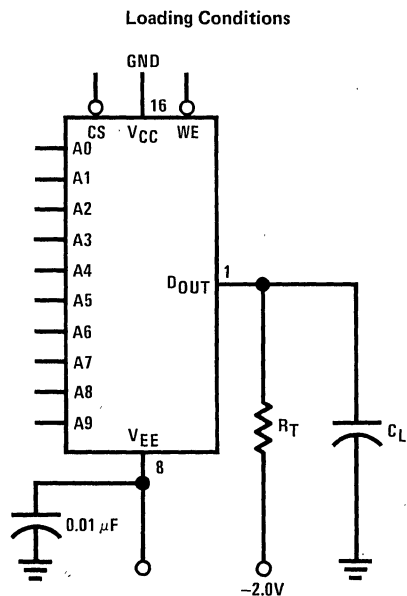
Read Mode



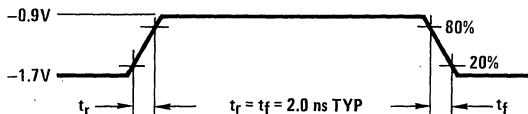
Switching Time Waveforms (Continued)



Test Conditions



Input Levels



All timing measurements referenced to 50% of input levels
 $C_L = 30 \text{ pF}$ including jig and stray capacitance
 $R_T = 50 \Omega$

DM10422 1024-Bit (256 × 4) ECL RAM

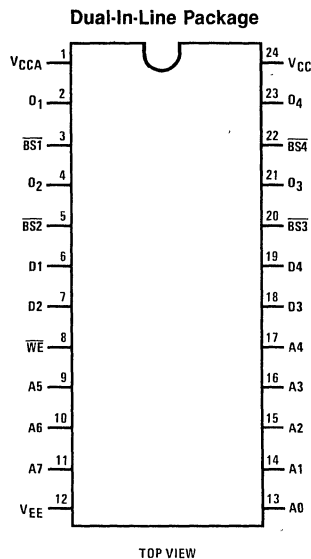
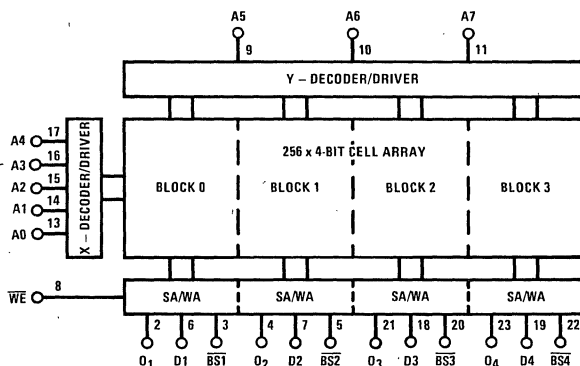
General Description

The DM10422 is normally a 256-word by 4-bit random access memory. However the memory has four Block Select (BS0-BS3) inputs which allow wire-ORing of any of the four blocks for a maximum 1024-word by 1-bit memory. The high speed access time allows its use in scratch pad, buffer, and control storage applications. The device is voltage compensated and is compatible with all 10k logic. Separate Data In and Data Out pins allow the set up of data for a write cycle while performing a read.

Features

- 4 separate Block Select inputs for configurations from 256 × 4 to 1024 × 1
- Maximum address access time—12 ns
- Typical Block Select access time—3.5 ns
- 10k logic compatible

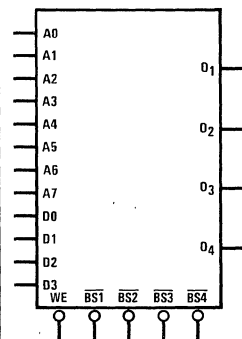
Block and Connection Diagrams



Pin Names

BS1-BS4	Block Selects
A0-A7	Address Inputs
WE	Write Enable
D1-D4	Data Inputs
O1-O4	Data Outputs

Logic Symbol



Order Number DM10422J
See NS Package J24E

Truth Table (Positive Logic)

Input			Output	Mode
BS	WE	DI		
H	X	X	L	Disable
L	L	L	L	Write "0"
L	L	H	L	Write "1"
L	H	X	Data	Read

Absolute Maximum Ratings

Supply Voltage, V_{EE} to V_{CC}	+ 0.5V to - 7.0V
Input Voltage, V_{IN}	+ 0.5V to V_{EE}
Output Current	- 30 mA
Storage Temperature, T_{stg}	- 65°C to + 150°C
Storage Temperature Under Bias, T_{stg} (Bias)	- 55°C to + 125°C

DC Electrical Characteristics $V_{EE} = -5.2V$, $R_L = 50\Omega$ to - 2.0V, $T_A = 0^\circ C$ to + 75°C, air flow exceeding 500 LFM

Symbol	Parameter	Conditions	Min	Typ	Max	Units		
V_{OH}	Output Voltage	$V_{IN} = V_{IHA}$ or V_{ILB}	0°C	- 1000	- 840	mV		
			25°C	- 960	- 810			
			75°C	- 900	- 720			
V_{OL}	0°C		- 1870	- 1665				
	25°C		- 1850	- 1650				
	75°C		- 1830	- 1625				
V_{OHC}	Output Threshold Voltage	$V_{IN} = V_{IHB}$ or V_{ILA}	0°C	- 1020		mV		
			25°C	- 980				
			75°C	- 920				
V_{OLC}	0°C			- 1645				
	25°C			- 1630				
	75°C			- 1605				
V_{IH}	Input Voltage	Guaranteed Input Voltage High for All Inputs	0°C	- 1145	- 840	mV		
			25°C	- 1105	- 810			
			75°C	- 1045	- 720			
V_{IL}	Guaranteed Input Voltage Low for All Inputs		0°C	- 1870	- 1490			
			25°C	- 1850	- 1475			
			75°C	- 1830	- 1450			
I_{IH}		Input Current	$V_{IN} = V_{IHA}$	0°C to 75°C		220	μA	
				\overline{BS}	$V_{IN} = V_{ILB}$	0°C to 75°C		0.5
						Other		- 50
I_{EE}	Supply Current	All Inputs and Outputs Open, Test Pin 12	0°C	- 200	- 160	mA		
			75°C		- 145			

AC Electrical Characteristics

$V_{EE} = -5.2V \pm 5\%$, $R_L = 50\Omega$ to - 2.0V, $T_A = 0^\circ C$ to + 75°C, air flow exceeding 500 LFM

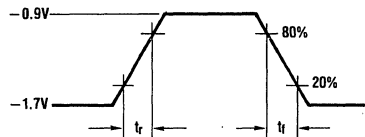
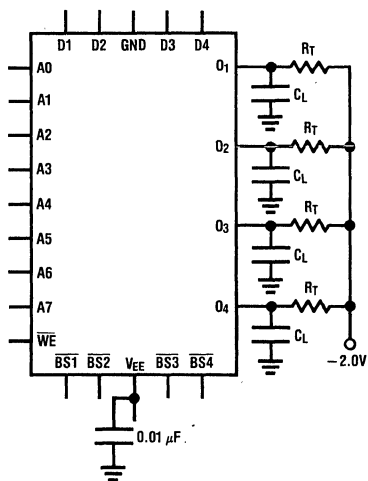
Symbol	Parameter	Conditions	Min	Typ	Max	Units
READ MODE						
t_{ABS}	Block Select Access Time				5.0	ns
t_{RBS}	Block Select Recovery Time				5.0	ns
t_{AA}	Address Access Time				12	ns
WRITE MODE						
t_W	Write Pulse Width	$t_{WSA} = 3$ ns	7			ns
t_{WSD}	Data Set-Up Time		2.0			ns
t_{WHD}	Data Hold Time		2.0			ns
t_{WSA}	Address Set-Up Time	$t_W = 7$ ns	3.0			ns
t_{WHA}	Address Hold Time		2.0			ns
t_{WSBS}	Block Select Set-Up Time		2.0			ns
t_{WHBS}	Block Select Hold Time		2.0			ns
t_{WS}	Write Disable Time				5	ns
t_{WR}	Write Recovery Time				7	ns

Electrical Characteristics (Continued)

$V_{EE} = -5.2V \pm 5\%$, $R_L = 50\Omega$ to $-2.0V$, $T_A = 0^\circ C$ to $+75^\circ C$, air flow exceeding 500 LFM

Symbol	Parameter	Conditions	Min	Typ	Max	Units
RISE/FALL TIME						
t_r	Output Rise Time			3		ns
t_f	Output Fall Time			3		ns
CAPACITANCE						
C_{IN}	Input Capacitance			4		pF
C_{OUT}	Output Capacitance			7		pF

Test Circuit and Input Waveform



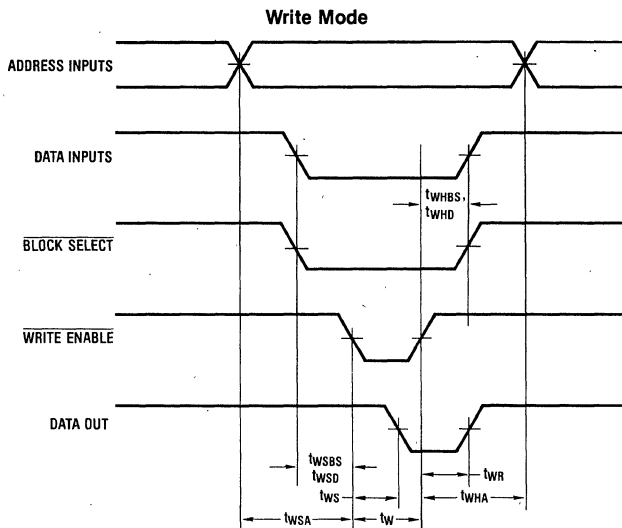
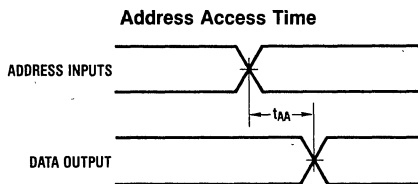
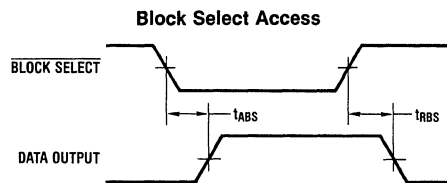
$t_r = t_f = 2.0 \text{ ns} \pm 10\%$

$R_T = 50\Omega$

$C_L = 30 \text{ pF}$

All timing measurements are referenced from 50% of input levels to 50% of input/output levels.

Switching Time Waveforms



DM10422A 1024-Bit (256 × 4) ECL RAM

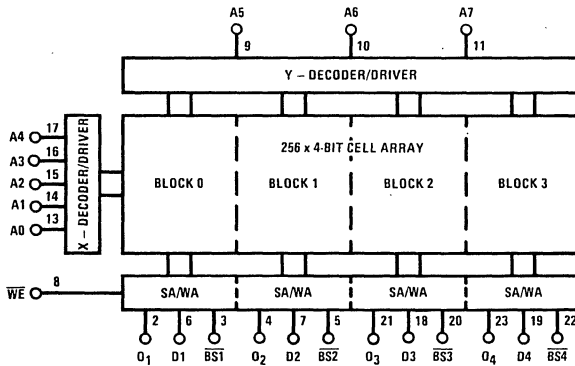
General Description

The DM10422A is normally a 256-word by 4-bit random access memory. However the memory has four Block Select (BS0-BS3) inputs which allow wire-ORing of any of the four blocks for a maximum 1024-word by 1-bit memory. The high speed access time allows its use in scratch pad, buffer, and control storage applications. The device is voltage compensated and is compatible with all 10k logic. Separate Data In and Data Out pins allow the set up of data for a write cycle while performing a read.

Features

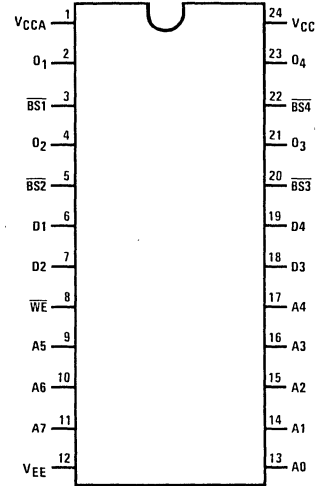
- 4 separate Block Select inputs for configurations from 256 × 4 to 1024 × 1
- Maximum address access time—10 ns
- Typical Block Select access time—3.5 ns
- 10k logic compatible

Block and Connection Diagrams



Pin Names
 BS1-BS4 Block Selects
 A0-A7 Address Inputs
 WE Write Enable
 D1-D4 Data Inputs
 O1-O4 Data Outputs

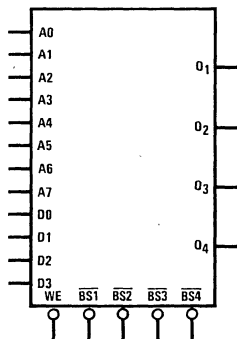
Dual-In-Line Package



TOP VIEW

Order Number DM10422AJ
See NS Package J24E

Logic Symbol



Truth Table (Positive Logic)

Input			Output	Mode
BS	WE	DI		
H	X	X	L	Disable
L	L	L	L	Write "0"
L	L	H	L	Write "1"
L	H	X	Data	Read

Absolute Maximum Ratings

Supply Voltage, V_{EE} to V_{CC}	+ 0.5V to - 7.0V
Input Voltage, V_{IN}	+ 0.5V to V_{EE}
Output Current	- 30 mA
Storage Temperature, T_{stg}	- 65°C to + 150°C
Storage Temperature Under Bias, T_{stg} (Bias)	- 55°C to + 125°C

DC Electrical Characteristics $V_{EE} = -5.2V$, $R_L = 50\Omega$ to - 2.0V, $T_A = 0^\circ C$ to + 75°C, air flow exceeding 500 LFM

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{OH}	Output Voltage	$V_{IN} = V_{IHA}$ or V_{ILB}	0°C	- 1000	- 840	mV
			25°C	- 960	- 810	
			75°C	- 900	- 720	
V_{OL}	0°C		- 1870	- 1665		
	25°C		- 1850	- 1650		
	75°C		- 1830	- 1625		
V_{OHC}	Output Threshold Voltage	$V_{IN} = V_{IHB}$ or V_{ILA}	0°C	- 1020		mV
			25°C	- 980		
			75°C	- 920		
V_{OLC}	0°C			- 1645		
	25°C			- 1630		
	75°C			- 1605		
V_{IH}	Input Voltage	Guaranteed Input Voltage High for All Inputs	0°C	- 1145	- 840	mV
			25°C	- 1105	- 810	
			75°C	- 1045	- 720	
V_{IL}	Input Voltage	Guaranteed Input Voltage Low for All Inputs	0°C	- 1870	- 1490	
			25°C	- 1850	- 1475	
			75°C	- 1830	- 1450	
I_{IH}	Input Current	$V_{IN} = V_{IHA}$	0°C to 75°C		220	μA
		\overline{BS} Other	$V_{IN} = V_{ILB}$	0°C to 75°C		
				- 50		
I_{EE}	Supply Current	All Inputs and Outputs Open, Test Pin 12	0°C	- 200	- 160	
			75°C		- 145	

AC Electrical Characteristics $V_{EE} = -5.2V$, $R_L = 50\Omega$ to - 2.0V, $T_A = 0^\circ C$ to + 75°C, air flow exceeding 500 LFM

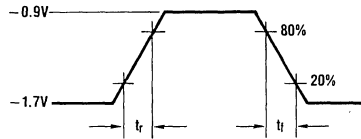
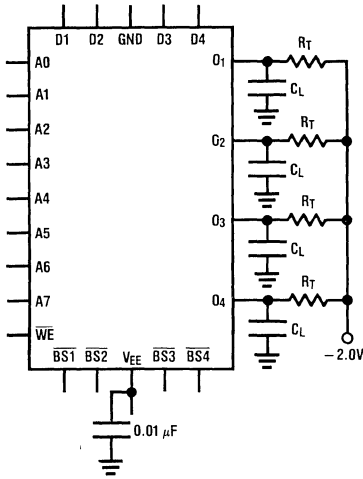
Symbol	Parameter	Conditions	Min	Typ	Max	Units
READ MODE						
t_{ABS}	Block Select Access Time			4	5.0	ns
t_{RBS}	Block Select Recovery Time			4	5.0	ns
t_{AA}	Address Access Time			8	10	ns
WRITE MODE						
t_W	Write Pulse Width	$t_{WSA} = 2$ ns	6	4		ns
t_{WSD}	Data Set-Up Time		2.0			ns
t_{WHD}	Data Hold Time		2.0			ns
t_{WSA}	Address Set-Up Time	$t_W = 6$ ns	2.0			ns
t_{WHA}	Address Hold Time		2.0			ns
t_{WSBS}	Block Select Set-Up Time		2.0			ns
t_{WHBS}	Block Select Hold Time		2.0			ns
t_{WS}	Write Disable Time				5	ns
t_{WR}	Write Recovery Time				7	ns

Electrical Characteristics (Continued)

$V_{EE} = -5.2V$, $R_L = 50\Omega$ to $-2.0V$, $T_A = 0^\circ C$ to $+75^\circ C$, air flow exceeding 500 LFM

Symbol	Parameter	Conditions	Min	Typ	Max	Units
RISE/FALL TIME						
t_r	Output Rise Time			3		ns
t_f	Output Fall Time			3		ns
CAPACITANCE						
C_{IN}	Input Capacitance			4		pF
C_{OUT}	Output Capacitance			7		pF

Test Circuit and Input Waveform



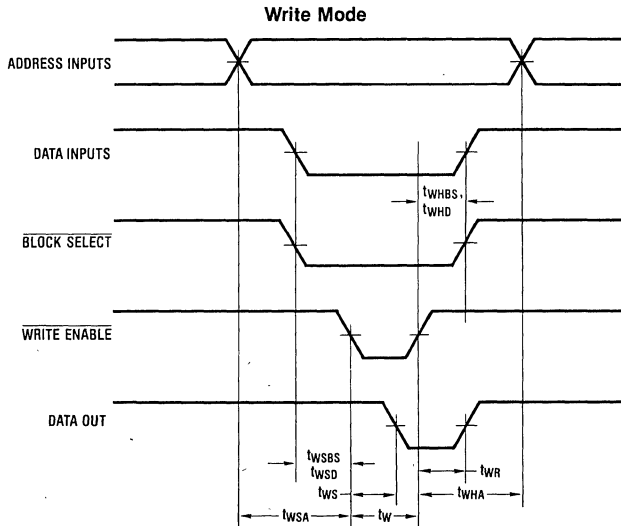
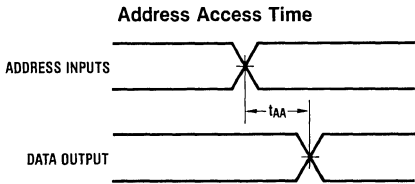
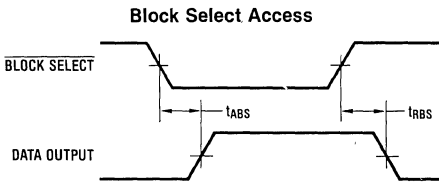
$t_r = t_f = 2.0 \text{ ns} \pm 10\%$

$R_T = 50\Omega$

$C_L = 30 \text{ pF}$

All timing measurements are referenced from 50% of input levels to 50% of input/output levels.

Switching Time Waveforms



DM10470 Standard, DM10470A High Speed, DM10470L Low Power 4096-Bit (4096 × 1) ECL RAMs

General Description

The DM10470 is a 4096-bit random access memory organized 4096-words by 1 bit. It is designed for high speed scratch pad and buffer storage applications. It is voltage and temperature compensated and compatible with all 10k logic. It has separate Data In and Data Out pins. The active low Chip Select \overline{CS} and unterminated emitter-follower outputs allow easy expansion.

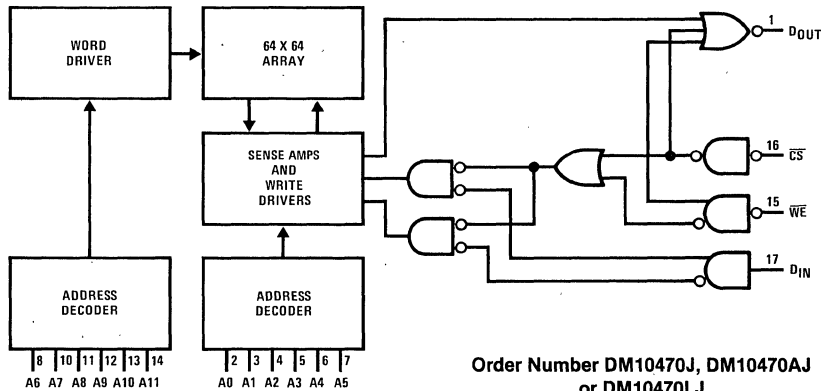
The DM10470 is speed and power selected to provide cost-performance benefits not available from any other manufacturer.

Features

- Three speed-power combinations for maximum cost-performance:

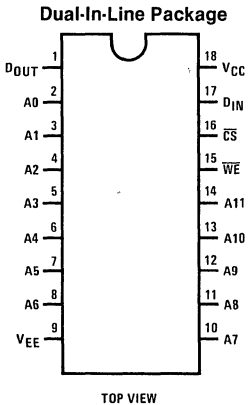
Standard DM10470	25 ns/200 mA max
High speed DM10470A	15 ns/200 mA max
Low power DM10470L	25 ns/130 mA max
- 10k logic compatible
- Unterminated emitter-follower outputs

Logic Diagram

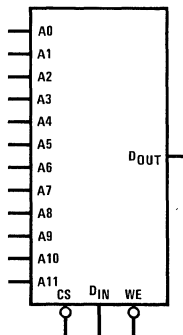


Order Number DM10470J, DM10470AJ or DM10470LJ
See NS Package J18A

Connection Diagram



Logic Symbol



Truth Table

Inputs			Output	Mode
\overline{CS}	\overline{WE}	D_{IN}	Open Emitter	
H	X	X	L	Not Selected
L	L	L	L	Write "0"
L	L	H	L	Write "1"
L	H	X	D_{OUT}	Read

Pin Names

- \overline{CS} Chip Select Input
- A0-A11 Address Inputs
- \overline{WE} Write Enable
- D_{IN} Data Input
- D_{OUT} Data Output

Absolute Maximum Ratings

Temperature Under Bias (Ambient)	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
V _{EE} Relative to V _{CC}	-7.0V to +0.5V
Any Input Relative to V _{CC}	V _{EE} to +0.5V
Output Current (Output High)	-30 mA to +0.1 mA
Lead Temperature (Soldering, 10 seconds)	300°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V _{EE})	-5.46	-4.94	V
Ambient Temperature (T _A)	0	+75	°C

DC Electrical Characteristics

V_{EE} = -5.2V, output load = 50Ω and 30 pF to -2.0V, T_A = 0°C to +75°C (Notes 1, 2, 3 and 4)

Symbol	Parameter	Conditions	T _A	B Limit	A Limit	Units
V _{OH}	Output Voltage High	V _{IN} = V _{IHA} or V _{ILB}	0°C +25°C +75°C	-1000 -960 -900	-840 -810 -720	mV
V _{OL}	Output Voltage Low	V _{IN} = V _{IHA} or V _{ILB}	0°C +25°C +75°C	-1870 -1850 -1830	-1665 -1650 -1625	mV
V _{OHC}	Output Voltage High	V _{IN} = V _{IHB} or V _{ILA}	0°C +25°C +75°C	-1020 -980 -920		mV
V _{OLC}	Output Voltage Low	V _{IN} = V _{IHB} or V _{ILA}	0°C +25°C +75°C		-1645 -1630 -1605	mV
V _{IH}	Input Voltage High	Guaranteed Input Voltage High for All Inputs	0°C +25°C +75°C	-1145 -1105 -1045	-840 -810 -720	mV
V _{IL}	Input Voltage Low	Guaranteed Input Voltage Low for All Inputs	0°C +25°C +75°C	-1870 -1850 -1830	-1490 -1475 -1450	mV
I _{IH}	Input Current High	V _{IN} = V _{IHA}	0°C to +75°C		220	μA
I _{IL}	Input Current Low, \overline{CS} All Others	V _{IN} = V _{ILB}	0°C to +75°C	0.5 to -50	170	μA

Note 1: Conditions for testing not shown in the tables are chosen to guarantee operation under worst-case conditions.

Note 2: The specified limits represent the worst-case value for the parameter. Since these worst-case values normally occur at the temperature extremes, additional noise immunity and guard banding can be achieved by decreasing the allowable system operating ranges.

Note 3: Guaranteed with transverse air flow exceeding 500 linear FPM and 2-minute warm-up period. Typical resistance values of the package are: θ_{JA} (junction to ambient) = 90°C/W (still air); θ_{JA} (junction to ambient) = 50°C/W (at 500 FPM air flow); θ_{JC} (junction to case) = 25°C/W.

Note 4: "A" indicates the most positive value, "B" indicates the most negative value.

AC Electrical Characteristics

$V_{EE} = -5.2V \pm 5\%$, output load = 50Ω , 30 pF to $-2.0V$, $T_A = 0^\circ\text{C}$ to $+75^\circ\text{C}$

Symbol	Parameter	Conditions	DM10470A			DM10470			DM10470L			Units
			Min	Typ (Note 6)	Max	Min	Typ (Note 6)	Max	Min	Typ (Note 6)	Max	
READ MODE												
t_{ACS}	Chip Select Access Time	Measured at 50% of Input to 50% of Output (Note 7)		4	8		5	10		5	10	ns
t_{RCS}	Chip Select Recovery Time		4	8		5	10		5	10	ns	
t_{AA}	Address Access Time		12	15		18	25		18	25	ns	
WRITE MODE												
t_W	Write Pulse Width (to Guarantee Writing) DM10470A DM10470/L	$t_{WSA} = 3\text{ ns}$ $t_{WSA} = 6\text{ ns}$	10			15			15			ns
t_{WSD}	Data Set-Up Time Prior to Write		2	1		2	1		2	1		ns
t_{WHD}	Data Hold Time After Write		2	0		2	0		2	0		ns
t_{WSA}	Address Set-Up Time Prior to Write DM10470A DM10470/L	$t_W = 10\text{ ns}$ $t_W = 15\text{ ns}$	3	1		3	1		3	1		ns
t_{WHA}	Address Hold Time After Write		2	0		2	0		2	0		ns
t_{WSCS}	Chip Select Set-Up Time Prior to Write		2	1		2	1		2	1		ns
t_{WHCS}	Chip Select Hold Time After Write		2	0		2	0		2	0		ns
t_{WS}	Write Disable Time	50% of Input to 50% of Output		5	8		5			5	8	ns
t_{WR}	Write Recovery Time			5	8		5			5	8	ns
RISE TIME AND FALL TIME												
t_r	Output Rise Time	Measured Between 20% and 80% Points		3			3			3		ns
t_f	Output Fall Time			3			3			3		ns

Capacitance

Symbol	Parameter	Conditions	DM10470A			DM10470			DM10470L			Units
			Min	Typ (Note 6)	Max	Min	Typ (Note 6)	Max	Min	Typ (Note 6)	Max	
C_{IN}	Input Pin Capacitance	Measure with a Pulse Technique		4	5		4	5		4	5	pF
C_{OUT}	Output Pin Capacitance			7	8		7	8		7	8	pF

Power Supply Current $V_{EE} = -5.2V$, output load = 50Ω and 30 pF to $-2.0V$

Symbol	Parameter	Conditions	DM10470A B Limit	DM10470 B Limit	DM10470L B Limit	Units
I_{EE}	Power Supply Current (Pin 8) (Note 5)	All Inputs and Outputs Open, $T_A = 25^\circ\text{C}$	-200	-200	-130	mA

Note 5: Typical values at $V_{EE} = -5.2V$; $T_A = 0^\circ\text{C}$, $I_{EE} = -145\text{ mA}$; $T_A = 25^\circ\text{C}$, $I_{EE} = 135\text{ mA}$; $T_A = 75^\circ\text{C}$, $I_{EE} = 125\text{ mA}$.

Note 6: Typical values are at $V_{EE} = -5.2V$, $T_A = 25^\circ\text{C}$ and maximum loading.

Note 7: The maximum address access time is guaranteed to be the worst-case bit in the memory using a pseudorandom testing pattern.

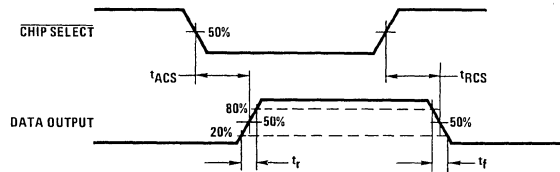
Functional Description

Addressing the DM10470/DM10470A is achieved by means of the 12 address lines, A0-A11. Each of the 2^{12} one-zero combinations of the address lines corresponds to a unique bit location in the memory. The memory array can be expanded to 8192 words without additional decoding, by using the active low Chip Select (\overline{CS}) and wire-ORing the unterminated emitter-follower outputs. A 50Ω resistor to $-2V$ (or an equivalent network) is required to provide a low at the output when the device is off. This termination is required for both single device or wire-ORed operation.

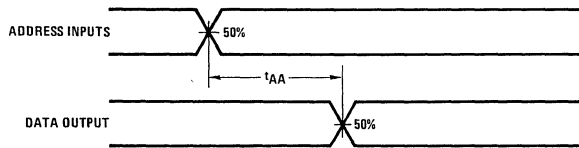
The device is selected with \overline{CS} low and deselected with \overline{CS} high. The operating mode is controlled by the active low Write Enable (\overline{WE}). \overline{WE} low causes the data at the Data Input (D_{IN}) to be stored at the selected address. \overline{WE} low also causes the output to be disabled (low due to the 50Ω pull-down resistor). \overline{WE} high causes the data stored at the selected address to be present at the Data Output (D_{OUT}) pin when \overline{CS} is low.

Switching Time Waveforms

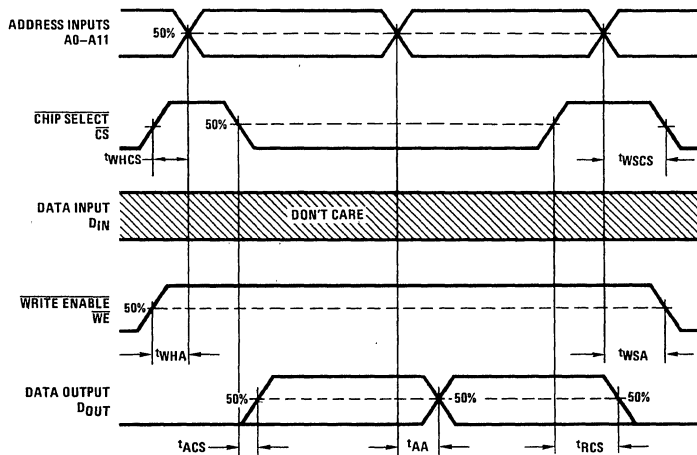
Chip Select Access Time



Address Access Time

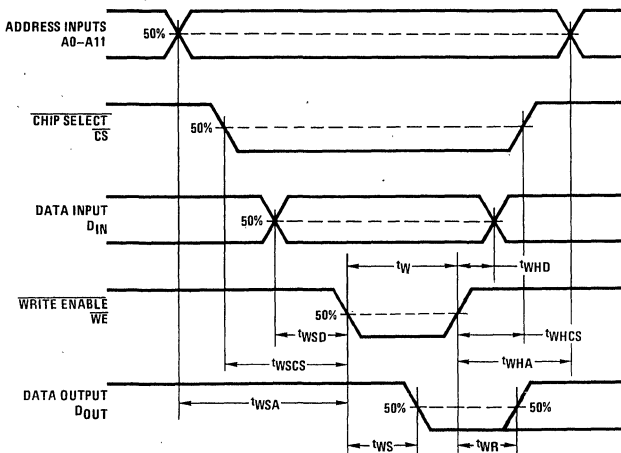


Read Mode



Switching Time Waveforms (Continued)

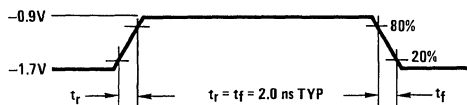
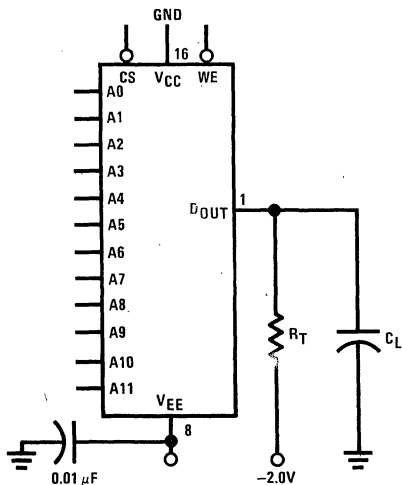
Write Mode



Test Conditions

Loading Conditions

Input Levels



All timing measurements referenced to 50% of input levels
 $C_L = 30$ pF including jig and stray capacitance
 $R_T = 50\Omega$

DM10474/DM10474A (1024 x 4) 4096-Bit, 10k ECL RAM

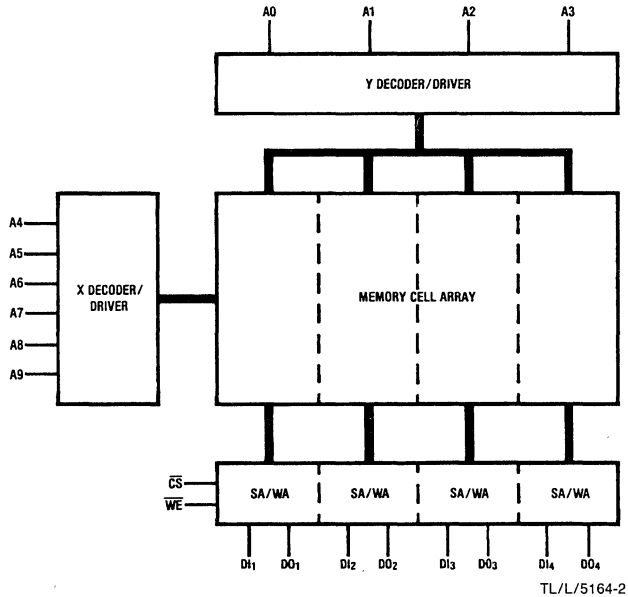
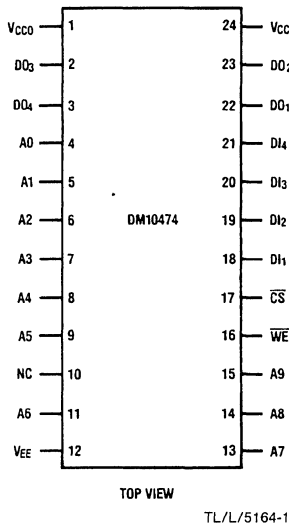
General Description

The DM10474 is a 4096-bit read/write random access memory, organized in the popular 1024 words by 4-bit configuration. The input and output levels are voltage compensated 10k ECL levels. The DM10474A has a maximum access time of 15 ns, and the DM10474 has a maximum access time of 25 ns.

Features

- 1024 words x 4-bit organization
- On chip voltage compensation for improved noise margin
- Fully compatible with industry standard 10k series ECL families
- Address access time: 25 ns max for standard part, 15 ns max for "A" part.
- Chip select access time: 10 ns max for standard part, 6 ns max for "A" part.
- Low power dissipation: -220 mA max for "A" part, -200 mA max for standard.
- Pin compatible with F10474 and MBM10474

Connection and Block Diagrams



Order Number DM10474J or DM10474AJ
See NS Package J24E

Truth Table

Inputs			Output		Mode
CS	WE	D _{IN}	Open Emitter		
H	X	X	L		Not Selected
L	L	L	L		WRITE "0"
L	L	H	L		WRITE "1"
L	H	X		D _{OUT}	READ

H = high voltage level
L = low voltage level
X = don't care

DC Electrical Characteristics

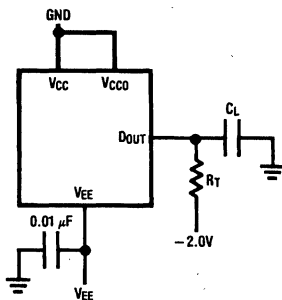
($V_{CC} = 0V$, $V_{EE} = -5.2V$, output load = 50Ω to $-2.0V$ and airflow ≥ 500 LFM unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
V_{OH}	Output High Voltage ($V_{IN} = V_{IH \text{ max}}$ or $V_{IL \text{ min}}$)	0°C	-1000		-840	mV
		25°C	-970		-810	
		75°C	-900		-720	
V_{OL}	Output Low Voltage ($V_{IN} = V_{IH \text{ max}}$ or $V_{IL \text{ min}}$)	0°C	-1870		-1665	mV
		25°C	-1850		-1650	
		75°C	-1830		-1625	
V_{OHC}	Output High Voltage ($V_{IN} = V_{IH \text{ min}}$ or $V_{IL \text{ max}}$)	0°C	-1020			mV
		25°C	-980			
		75°C	-920			
V_{OLC}	Output Low Voltage ($V_{IN} = V_{IH \text{ min}}$ or $V_{IL \text{ max}}$)	0°C			-1645	mV
		25°C			-1630	
		75°C			-1605	
V_{IH}	Input High Voltage (Guaranteed Input Voltage High for All Inputs)	0°C	-1145		-840	mV
		25°C	-1105		-810	
		75°C	-1045		-720	
V_{IL}	Input Low Voltage (Guaranteed Input Voltage Low for All Inputs)	0°C	-1870		-1490	mV
		25°C	-1850		-1475	
		75°C	-1830		-1450	
I_{IH}	Input High Current ($V_{IN} = V_{IH \text{ max}}$)	0° to 75°C			220	μA
I_{IL}	Input Low Current ($V_{IN} = V_{IL \text{ min}}$)	0° to 75°C	-50			μA
I_{IL}	\overline{CS} Input Low Current ($V_{IN} = V_{IL \text{ min}}$)	0° to 75°C	0.5		170	μA
I_{EE}	Power Supply Current (All Inputs and Outputs Open)	0° to 75°C	-200 -220*			mA

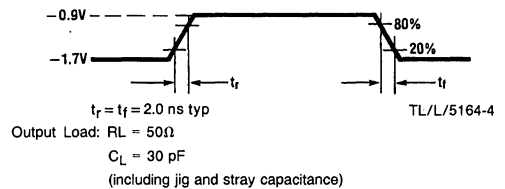
*For the DM10474A,

AC Test Circuit and Switching Time Waveform

(Full guaranteed operating ranges, output load = 50Ω to $-2.0V$ and 30 pF to GND and airflow ≥ 500 LFM unless otherwise noted.)



TL/L/5164-3

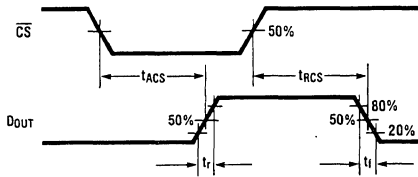


Note: All timing measurements referenced to 50% input levels.

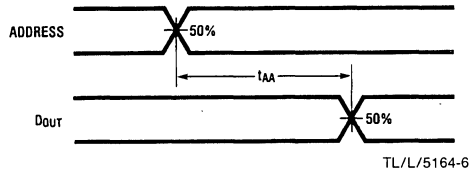
Read Cycle

Symbol	Parameter	DM10474		DM10474A		Units
		Typ	Max	Typ	Max	
t_{AA}	Address Access Time		25		15	ns
t_{ACS}	Chip Select Access Time		10		6	ns
t_{RCS}	Chip Select Recovery Time	10		6		ns

Read Cycle Timing Diagrams



TL/L/5164-5

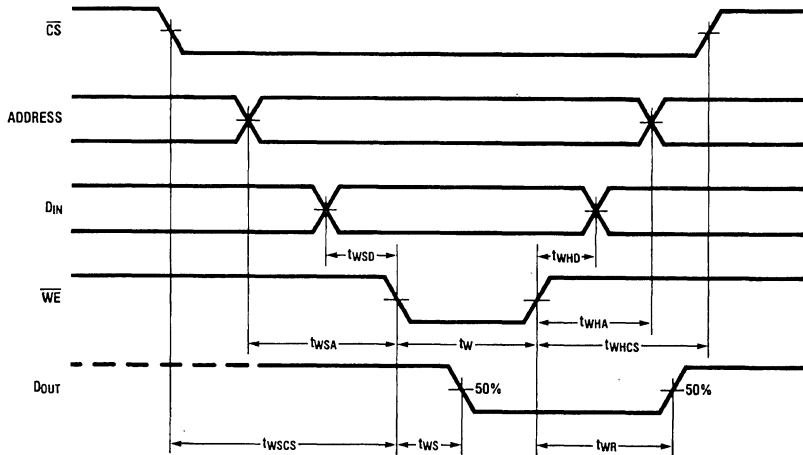


TL/L/5164-6

Write Cycle

Symbol	Parameter	DM10474			DM10474A			Units
		Min	Typ	Max	Min	Typ	Max	
t_w	Write Pulse Width			12			8	ns
t_{WS}	Write Disable Time		4					ns
t_{WR}	Write Recovery Time		4					ns
t_{WSA}	Address Set Up Time		0					ns
t_{WSCS}	Chip Select Set Up Time		0					ns
t_{WSD}	Data Set Up Time		0					ns
t_{WHA}	Address Hold Time		0					ns
t_{WHCS}	Chip Select Hold Time		0					ns
t_{WHD}	Data Hold Time		0					ns

Write Cycle Timing Diagrams



TL/L/5164-7

Rise Time and Fall Time

Symbol	Parameter	DM10474/DM10474A			Units
		Min	Typ	Max	
t_r	Output Rise Time	—	2.5	—	ns
t_f	Output Fall Time	—	2.5	—	ns



Section 23 2900 Family/ Bipolar Microprocessor

23

DEVICE	DESCRIPTION	PAGE NUMBER
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Introduction

Since its introduction in 1976, the 2900 Family of Bipolar Microprocessor Components has rapidly established itself as the industry standard for bit-slice, microprogrammable system design. National Semiconductor is pleased to have contributed to the success of this family by providing the highest performance components available from any manufacturer. We are firmly committed to continuing this emphasis on performance, since we feel that designers of bipolar systems will continue to demand increased component speed as their system throughput requirements increase. We are not only dedicated to providing components, but also to developing the design techniques that optimize their use in systems. This is evidenced by the expanded Applications section in this book.

To achieve this higher performance, National developed a design technique referred to as SCL¹ and introduced its first 2900 Family product—the IDM2901A—in 1977. This device featured AC characteristics that were 25% faster than anything on the market at that time. In 1978, a speed-selected version of the 2901A—the IDM2901A-1—was introduced. This device further improved performance by an additional 15%. In 1982 an additional 30% performance improvement was provided by the IDM2901A-2, a device that combines the SCL design technique with the latest advances in bipolar LSI processing. All of this has been accomplished without a single compromise with regard to functionality or DC characteristics. In fact, power dissipation in all cases is equal to or less than that of the competing Low Power Schottky devices.

Following its success with the IDM2901, National applied the SCL design technique to the IDM2909A, IDM2910A, IDM2911A, and IDM29705A. These devices also have speed characteristics that are 30%–50% better than those of the competing LS versions.

Not content to simply second source existing 2900 functions, National has also added to the family additional devices that were found to be significantly useful in bit-slice microprocessor design. These include devices from other National product lines — such as the Bipolar Memory and Octal Logic devices found in this book — and certain proprietary functions, such as the 29903 16 × 4 Edge-Triggered Register File.

Even more significantly, National will begin to develop new bit-slices and microsequencers that are architecturally different from other products on the market.

These products, plus other products currently in development, make use of the SCL design philosophy. By using SCL, National has not only set a standard of performance for the 2900 Family that other manufacturers are attempting to duplicate, but also is providing you—the design engineer—with components that allow you to build the highest performance systems possible using bipolar LSI technology.

1. SCL is a design technique that combines the performance advantages of ECL with Low Power Schottky input and output compatibility. For a more detailed description, see the Applications section.

**IDM2901A, IDM2901A-1/IDM2901A-2
4-Bit Bipolar Microprocessor**

General Description

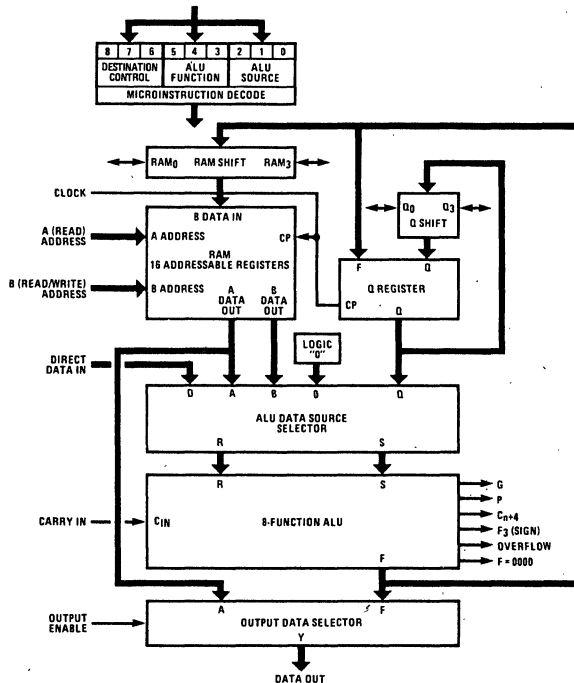
The IDM2901 4-bit bipolar microprocessor slice is a cascadable device designed for use in Central Processing Units, programmable microprocessors, peripheral controllers, and other "high-speed" applications where economy, hardware/software flexibility, and easy expansion are system prerequisites. The building-block architecture and microinstruction format of the IDM2901 permit efficient emulation of most digital-based systems.

As shown in the simplified block diagram, the IDM2901 device consists of a 16-word by 4-bit 2-port RAM, a high-speed ALU, and the required shifting, decoding, and multiplexing circuits. The 9-bit microinstruction word is organized into three groups of three bits each — the first group (bits 0-2) selects ALU source operands, the second group (bits 3-5) selects the ALU function, and the last group (bits 6-8) selects the destination register within the ALU. The slice microprocessor is cascadable with full look-ahead or ripple carry; all outputs are TRI-STATE® and four status-flag outputs are available. To minimize power consumption and to maximize speed and reliability, the 40-pin LSI chip is fabricated using a National state-of-the-art Low-Power Schottky technology called "SCL".

Features and Benefits

- **Multiple-address architecture** — improves system speed by providing simultaneous yet independent access to two working registers.
- **Multifunction ALU** — performs addition, two subtraction operations, and five logic functions on two source operands.
- **Flexible data-source selection** — for every ALU function, data is selected from five source ports for a total of 203 source operand pairs.
- **Left/right shift independent of ALU** — an arithmetic operation and a left or right shift can be obtained on the same machine cycle.
- **Four status flags** — carry, overflow, zero, and functional sign are available as outputs.
- **Expandable** — Connect any number of IDM2901s together for longer word lengths.
- **Microprogrammable** — three groups of 3 bits each for source operand, ALU function, and destination control.

Block Diagram



Absolute Maximum Ratings

Storage Temperature	-65°C to +150°C
Temperature (Ambient) Under Bias	-55°C to +125°C
Supply Voltage to Ground Potential	-0.5 V to +6.3 V
DC Voltage Applied to Outputs for High Output State	-0.5 V to +V _{CC} max
DC Input Voltage	-0.5 V to +5.5 V
DC Output Current, into Outputs	30 mA
DC Input Current	-30 mA to +5.0 mA

Operating Range

P/N	Temperature	V _{CC}
IDM2901 JC, NC	T _A = 0°C to +70°C	4.75V to 5.25V
IDM2901 JM, JM/883	T _C = -55°C to +125°C	4.50V to 5.50V
IDM2901A-1 JC, NC	T _A = 0°C to +70°C	4.75V to 5.25V
IDM2901A-1 JM, JM/883	T _C = -55°C to +125°C	4.50V to 5.50V

Standard Screening (Conforms to MIL-STD-883 for Class C parts)

Step	MIL-STD-883 Method	Conditions	Level	
			JC, NC	JM
Pre-Seal Visual Inspection	2010	B	100%	100%
Stabilization Bake	1008	C: 24-hour 150°C	100%	100%
Temperature Cycle	1010	C: -65°C to +150°C 10 cycles	100%	100%
Centrifuge	2001	B: 10,000 G	100%*	100%
Fine Leak	1014	A: 5 x 10 ⁻⁸ atm-cc/cm ³	100%*	100%
Gross Leak	1014	C2: Fluorocarbon	100%*	100%
Electrical Test Subgroups 1 and 7 and 9	5004	See below for definitions of subgroups	100%	100%
Insert Additional Screening here for Class B Parts				
Group A Sample Tests Subgroup 1 Subgroup 2 Subgroup 3 Subgroup 7 Subgroup 8 Subgroup 9	5005	See below for definitions of subgroups	LTPD = 5 LTPD = 7 LTPD = 7 LTPD = 7 LTPD = 7 LTPD = 7	LTPD = 5 LTPD = 7 LTPD = 7 LTPD = 5 LTPD = 7 LTPD = 5

*Not applicable to IDM2901ANC.

Additional Screening for Class B Parts

Step	MIL-STD-883 Method	Conditions	Level
			JM/883
Burn-In	1015	D: 125°C, 160 hours min	100%
Electrical Test Subgroup 1	5004		100%
Subgroup 2			100%
Subgroup 3			100%
Subgroup 7			100%
Subgroup 9			100%
Return to Group A Tests in Standard Screening			

Group A Subgroups

(as defined in MIL-STD-883, method 5005)

Subgroup	Parameter	Temperature
1	DC	25°C
2	DC	Maximum rated temperature
3	DC	Minimum rated temperature
7	Function	25°C
8	Function	Maximum and minimum rated temperature
9	Switching	25°C
10	Switching	Maximum rated temperature
11	Switching	Minimum rated temperature

Electrical Characteristics Over Operating Range IDM2901A/IDM2901A-1

Symbol	Description	Test Conditions (Note 1)	Min	Typ (Note 2)	Max	Units
V _{OH}	Output High Voltage	V _{CC} = min V _{IN} = V _{IH} or V _{IL}	I _{OH} = -1.6 mA; Y ₀ /Y ₁ /Y ₂ /Y ₃	2.4		V
			I _{OH} = -1.0 mA; C _{n+4}	2.4		
			I _{OH} = -800 μA; OVR/P	2.4		
			I _{OH} = -600 μA; F ₃	2.4		
			I _{OH} = -600 μA; RAM _{0,3} /Q _{0,3}	2.4		
			I _{OH} = -1.6 mA; G	2.4		

Electrical Characteristics (cont'd.)

Symbol	Description	Test Conditions (Note 1)	Min	Typ (Note-2)	Max	Units		
I _{CEX}	Output Leakage Current for F = 0 Output	V _{CC} = min; V _{OH} = 5.5 V, V _{IN} = V _{IH} or V _{IL}			250	μA		
V _{OL}	Output Low Voltage	V _{CC} = min; V _{IN} = V _{IH} or V _{IL}	I _{OL} = 20 mA (Com'1) Y ₀ /Y ₁ /Y ₂ /Y ₃		0.5	V		
			I _{OL} = 16 mA (Mil); Y ₀ /Y ₁ /Y ₂ /Y ₃		0.5			
			I _{OL} = 16 mA; G/F = 0		0.5			
			I _{OL} = 10 mA; C _{n+4}		0.5			
			I _{OL} = 10 mA; OVR/P		0.5			
			I _{OL} = 8 mA; F ₃ /RAM _{0,3} /Q _{0,3}		0.5			
V _{IH}	Input High Level	Guaranteed input logical high voltage for all inputs	2.0			V		
V _{IL}	Input Low Level	Guaranteed input logical low voltage for all inputs			0.8	V		
V _I	Input Clamp Voltage	V _{CC} = min; I _{IN} = -18 mA			-1.5	V		
I _{IL}	Input Low Current	V _{CC} = max; V _{IN} = 0.5 V	Clock/OE/C _n		-0.36	mA		
			A ₀ /A ₁ /A ₂ /A ₃		-0.36			
			B ₀ /B ₁ /B ₂ /B ₃		-0.36			
			D ₀ /D ₁ /D ₂ /D ₃		-0.36			
			I ₀ /I ₁ /I ₂ /I ₆		-0.36			
			I ₃ /I ₄ /I ₅		-0.36			
			I ₇ /I ₈		-0.36			
			RAM _{0,3} /Q _{0,3} (Note 4)		-0.36			
I _{IH}	Input High Current	V _{CC} = max; V _{IN} = 2.7 V	Clock/OE		20	μA		
			A ₀ /A ₁ /A ₂ /A ₃		20			
			B ₀ /B ₁ /B ₂ /B ₃		20			
			D ₀ /D ₁ /D ₂ /D ₃		20			
			I ₀ /I ₁ /I ₂ /I ₆ /I ₈		20			
			I ₃ /I ₄ /I ₅ /I ₇		20			
			RAM _{0,3} /Q _{0,3} (Note 4)		100			
			C _n		20			
I _I	Input High Current	V _{CC} = max; V _{IN} = 5.5 V			1.0	mA		
I _{OZH} , I _{OZL}	Off State (High Impedance) Output Current	V _{CC} = max	Y ₀ /Y ₁ /Y ₂ /Y ₃	V _O = 2.4 V	50	μA		
				V _O = 0.5 V	-50			
			RAM _{0,3} /Q _{0,3}	V _O = 2.4 V (Note 4)	100			
				V _O = 0.5 V (Note 4)	-360			
I _{OS}	Output Short Circuit Current (Note 3)	V _{CC} = 5.75 V V _O = 0.5 V	Y ₀ /Y ₁ /Y ₂ /Y ₃ /G	-30	-85	mA		
			C _{n+4}	-30	-85			
			OVR/P	-30	-85			
			F ₃	-30	-85			
			RAM _{0,3} /Q _{0,3}	-30	-85			
I _{CC}	Power Supply Current (Note 6)	V _{CC} = max	JC	T _A = 25°C	160	245	mA	
				T _A = 0°C to +70°C	160	260		
				T _A = +70°C	160	220		
				JM	T _C = -55°C to +125°C	160		275
					T _C = +125°C	160		185

Note 1: For conditions shown as min or max, use the appropriate value specified under Electrical Characteristics for the applicable device type.

Note 2: Typical limits are at V_{CC} = 5.0 V, 25°C ambient, and maximum loading.

Note 3: Not more than one output should be shorted at a time. Duration of the short circuit test should not exceed one second.

Note 4: These are TRI-STATE outputs internally connected to PNP inputs. Input characteristics are measured with I_{6,7,8} in a state such that the TRI-STATE output is off (high-impedance).

Note 5: "Mil" = IDM2901 JM, JM/883; "Com'1" = IDM2901 JC, NC.

Note 6: Worst case I_{CC} is at minimum temperature.

Absolute Maximum Ratings

Storage Temperature	-65°C to +150°C
Temperature (Ambient) Under Bias	-55°C to +125°C
Supply Voltage to Ground Potential	-0.5 V to +6.3 V
DC Voltage Applied to Outputs for High Output State	-0.5 V to +V _{CC} max
DC Input Voltage	-0.5 V to +5.5 V
DC Output Current, into Outputs	30 mA
DC Input Current	-30 mA to +5.0 mA

Operating Range

P/N	Temperature	V _{CC}
IDM2901A-2 JC, NC	T _A = 0°C to +70°C	4.75V to 5.25V
IDM2901A-2 JM	T _C = -55°C to +125°C	4.50V to 5.50V
IDM2901A-2 JM/883	T _C = -55°C to +125°C	4.50V to 5.50V

Standard Screening (Conforms to MIL-STD-883 for Class C parts)

Step	MIL-STD-883 Method	Conditions	Level	
			JC, NC	JM
Pre-Seal Visual Inspection	2010	B	100%	100%
Stabilization Bake	1008	C: 24-hour 150°C	100%	100%
Temperature Cycle	1010	C: -65°C to +150°C 10 cycles	100%	100%
Centrifuge	2001	B: 10,000 G	100%*	100%
Fine Leak	1014	A: 5 x 10 ⁻⁸ atm-cc/cm ³	100%*	100%
Gross Leak	1014	C2: Fluorocarbon	100%*	100%
Electrical Test Subgroups 1 and 7 and 9	5004	See below for definitions of subgroups	100%	100%
Insert Additional Screening here for Class B Parts				
Group A Sample Tests	5005	See below for definitions of subgroups	LTPD = 5	LTPD = 5
Subgroup 1			LTPD = 7	LTPD = 7
Subgroup 2			LTPD = 7	LTPD = 7
Subgroup 3			LTPD = 7	LTPD = 7
Subgroup 7			LTPD = 7	LTPD = 5
Subgroup 8			LTPD = 7	LTPD = 7
Subgroup 9			LTPD = 7	LTPD = 5

*Not applicable to IDM2901A-2 NC

Additional Screening for Class B Parts

Step	MIL-STD-883 Method	Conditions	Level
			JM/883
Burn-In	1015	D: 125°C, 160 hours min	100%
Electrical Test	5004		100%
Subgroup 1			100%
Subgroup 2			100%
Subgroup 3			100%
Subgroup 7			100%
Subgroup 9			100%
Return to Group A Tests in Standard Screening			

Group A Subgroups

(as defined in MIL-STD-883, method 5005)

Subgroup	Parameter	Temperature
1	DC	25°C
2	DC	Maximum rated temperature
3	DC	Minimum rated temperature
7	Function	25°C
8	Function	Maximum and minimum rated temperature
9	Switching	25°C
10	Switching	Maximum rated temperature
11	Switching	Minimum rated temperature

Electrical Characteristics Over Operating Range IDM2901A-2

Symbol	Description	Test Conditions (Note 1)	Min	Typ (Note 2)	Max	Units
V _{OH}	Output High Voltage	V _{CC} = min V _{IN} = V _{IH} or V _{IL}	I _{OH} = -1.6 mA; Y ₀ /Y ₁ /Y ₂ /Y ₃	2.4		V
			I _{OH} = -1.0 mA, C _{n+4}	2.4		
			I _{OH} = -800 μA; OVR/P	2.4		
			I _{OH} = -600 μA; F ₃	2.4		
			I _{OH} = -600 μA; RAM _{0,3} /Q _{0,3}	2.4		
			I _{OH} = -1.6 mA; G	2.4		

Electrical Characteristics (continued)

Symbol	Description	Test Conditions (Note 1)	Min	Typ (Note 2)	Max	Units	
I _{CEX}	Output Leakage Current for F = 0 Output	V _{CC} = min; V _{OH} = 5.5 V, V _{IN} = V _{IH} or V _{IL}			250	μA	
V _{OL}	Output Low Voltage	V _{CC} = min; V _{IN} = V _{IH} or V _{IL}	I _{OL} = 20 mA (Com ¹) Y ₀ /Y ₁ /Y ₂ /Y ₃		0.5	V	
			I _{OL} = 16 mA (Mil); Y ₀ /Y ₁ /Y ₂ /Y ₃		0.5		
			I _{OL} = 16 mA; \bar{G}/\bar{F} = 0		0.5		
			I _{OL} = 10 mA; C _{n+4}		0.5		
			I _{OL} = 10 mA; OVR/ \bar{P}		0.5		
			I _{OL} = 8 mA; F ₃ /RAM _{0,3} /Q _{0,3}		0.5		
V _{IH}	Input High Level	Guaranteed input logical high voltage for all inputs	2.0			V	
V _{IL}	Input Low Level	Guaranteed input logical low voltage for all inputs			0.8	V	
V _I	Input Clamp Voltage	V _{CC} = min; I _{IN} = -18 mA			-1.5	V	
I _{IL}	Input Low Current	V _{CC} = max, V _{IN} = 0.5 V	Clock/ $\bar{O}\bar{E}$ /C _n		-0.36	mA	
			A ₀ /A ₁ /A ₂ /A ₃		-0.36		
			B ₀ /B ₁ /B ₂ /B ₃		-0.36		
			D ₀ /D ₁ /D ₂ /D ₃		-0.36		
			I ₀ /I ₁ /I ₂ /I ₆		-0.36		
			I ₃ /I ₄ /I ₅		-0.36		
			I ₇ /I ₈		-0.36		
			RAM _{0,3} /Q _{0,3} (Note 4)		-0.36		
I _{IH}	Input High Current	V _{CC} = max; V _{IN} = 2.7 V	Clock/ $\bar{O}\bar{E}$		20	μA	
			A ₀ /A ₁ /A ₂ /A ₃		20		
			B ₀ /B ₁ /B ₂ /B ₃		20		
			D ₀ /D ₁ /D ₂ /D ₃		20		
			I ₀ /I ₁ /I ₂ /I ₆ /I ₈		20		
			I ₃ /I ₄ /I ₅ /I ₇		20		
			RAM _{0,3} /Q _{0,3} (Note 4)		100		
			C _n		20		
I _I	Input High Current	V _{CC} = max; V _{IN} = 5.5 V			1.0	mA	
I _{OZH} , I _{OZL}	Off State (High Impedance) Output Current	V _{CC} = max	Y ₀ /Y ₁ /Y ₂ /Y ₃	V _O = 2.4 V	50	μA	
				V _O = 0.5 V	-50		
RAM _{0,3} /Q _{0,3}				V _O = 2.4 V (Note 4)	100		
				V _O = 0.5 V (Note 4)	-360		
I _{OS}	Output Short Circuit Current (Note 3)	V _{CC} = 5.75 V V _O = 0.5 V	Y ₀ /Y ₁ /Y ₂ /Y ₃ / \bar{G}	-30	-85	mA	
			C _{n+4}	-30	-85		
			OVR/ \bar{P}	-30	-85		
			F ₃	-30	-85		
			RAM _{0,3} /Q _{0,3}	-30	-85		
I _{CC}	Power Supply Current (Note 6)	V _{CC} = max	T _A = 25°C	160	250	mA	
			JC	T _A = 0°C to +70°C	160		265
			JM	T _C = -55°C to +125°C	160		280
			T _C = +125°C	160	190		

Note 1: For conditions shown as min or max, use the appropriate value specified under Electrical Characteristics for the applicable device type.

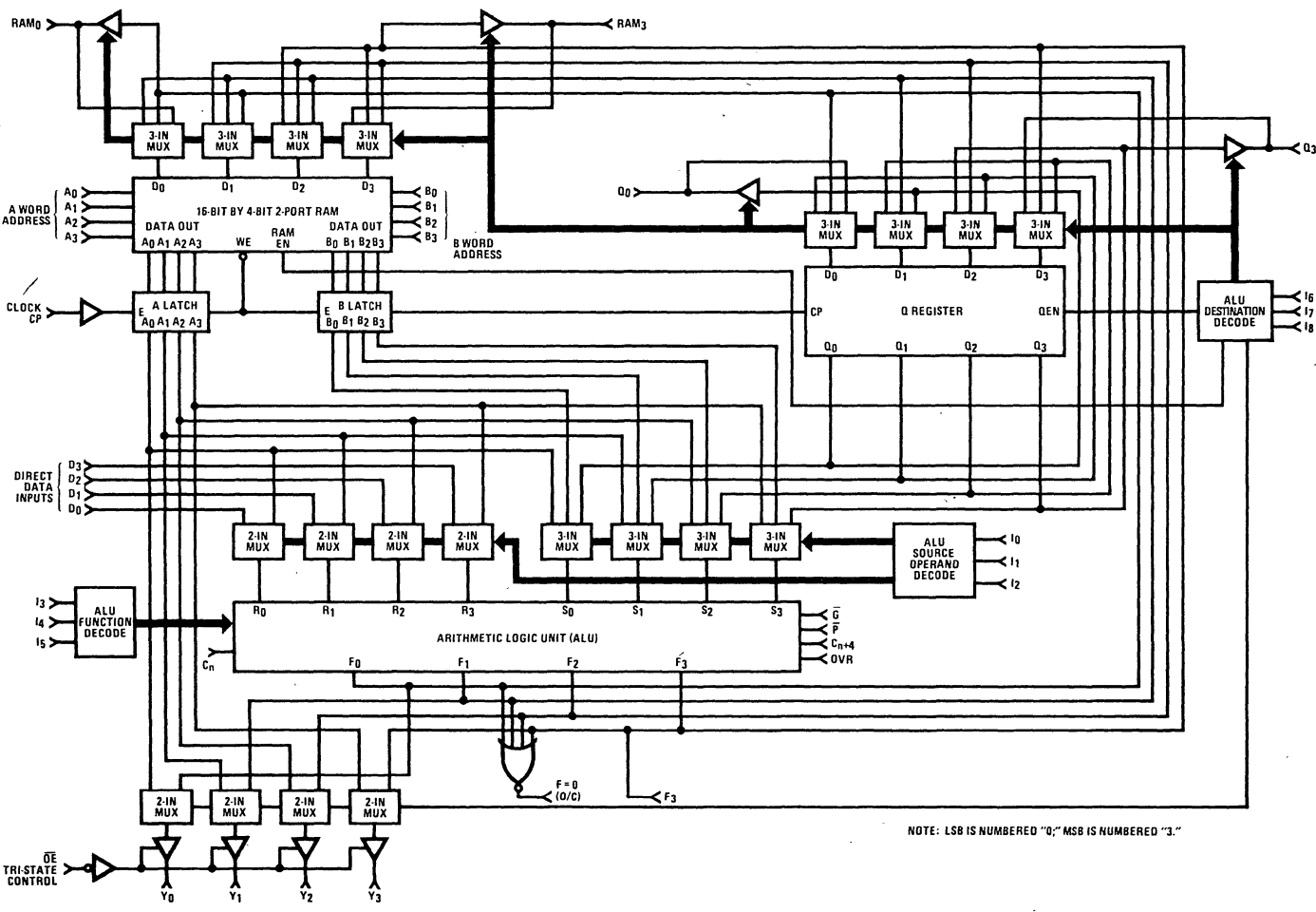
Note 2: Typical limits are at V_{CC} = 5.0 V, 25°C ambient, and maximum loading.

Note 3: Not more than one output should be shorted at a time. Duration of the short circuit test should not exceed one second.

Note 4: These are TRI-STATE outputs internally connected to PNP inputs. Input characteristics are measured with I_{6,7,8} in a state such that the TRI-STATE output is off (high-impedance).

Note 5: "Mil" = IDM2901A-2 JM, JM/883; "Com¹" = IDM2901A-2 JC, NC.

Note 6: Worst case I_{CC} is at minimum temperature.



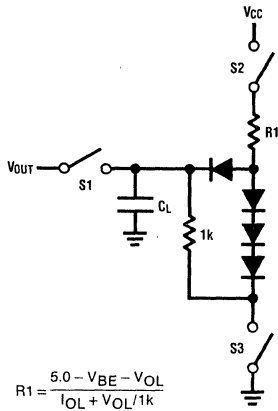
NOTE: LSB IS NUMBERED "0," MSB IS NUMBERED "3."

Figure 1. IDM2901 Microprocessor, Detailed Block Diagram

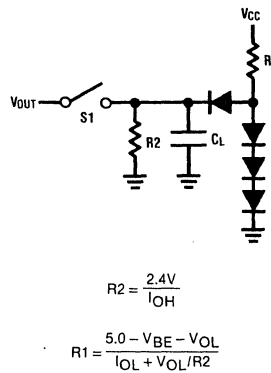
23-9

Test Output Load Configurations for IDM2901A, A-1, A-2

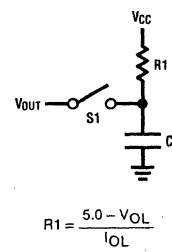
A. Three-State Outputs



B. Normal Outputs



C. Open-Collector Outputs



Note 1: $C_L = 50$ pF includes scope probe, wiring and stray capacitances without device in test fixture.

Note 2: S1, S2, S3 are closed during function tests and all AC tests except output enable tests.

Note 3: S1 and S3 are closed while S2 is open for t_{pZH} test.

S1 and S2 are closed while S3 is open for t_{pZL} test.

Note 4: $C_L = 5.0$ pF for output disable tests.

TESTING CONSIDERATIONS

Incoming test procedures on this device should be carefully planned, taking into account the high complexity and power levels of the part. The following notes may be useful.

1. Insure the part is adequately decoupled at the test head. Large changes in V_{CC} current as the device switches may cause erroneous function failures due to V_{CC} changes.
2. Do not leave inputs floating during any tests, as they may start to oscillate at high frequency.
3. Do not attempt to perform threshold tests at high speed. Following an input transition, ground current may change by as much as 400 mA in 5 ns–8 ns. Inductance in the ground cable may allow the ground pin at the device to rise by 100s of millivolts momentarily.

4. Use extreme care in defining input levels for AC tests. Many inputs may be changed at once, so there will be significant noise at the device pins and they may not actually reach V_{IL} or V_{IH} until the noise has settled. National recommends using $V_{IL} \leq 0.4V$ and $V_{IH} \geq 2.4V$ for AC tests.
5. To simplify failure analysis, programs should be designed to perform DC, Function, and AC tests as three distinct groups of tests.

Test Output Loads for IDM2901A, A-1, A-2

Pin #	Pin Label	Test Circuit	R1	R2
3	RAM ₃	A	560	1k
5	RAM ₀	A	560	1k
7	F = 0	C	270	—
13	Q ₃	A	560	1k
18	Q ₀	A	560	1k
28	F ₃	B	620	3.9k
29	G	B	220	1.5k
30	C _{n+4}	B	360	2.4k
31	OVR	B	470	3k
32	P	B	470	3k
33–36	Y _{0–3}	A	220	1k

Architecture

Figure 1 shows a detailed block diagram of the IDM2901. Observe that all data paths are 4 bits wide; however, the 4-bit slice can be cascaded to the number of bits required for a particular application. Although all parts of the bipolar device are important, the two key elements are the 16-word by 4-bit 2-port RAM and the high-speed ALU.

Any one of the 16 words in RAM can be read from the A-port (A₃-A₀) or the B-port (B₃-B₀); the selected word for the A-port is determined by the 4-bit A-address field, whereas the B-address field controls the output of the B-port. If the two address codes are identical, the same file data appears simultaneously at both output ports (A and B).

When enabled by RAM EN, new data is written into the file "word" defined by the B-address field; the write function is implemented when the clock input is low.

Each bit of data to be written is input via a 3-input multiplexer; this scheme permits shifting up one bit position (from LSB towards MSB), shifting down one bit position (from MSB towards LSB), or not shifting at all. A similar scheme is used when data is written into the "Q" register.

Each of the A and B data ports drives an associated 4-bit latch. These latches hold the RAM data while the clock input is low; consequently, any possibility of race conditions when writing new data is eliminated.

The high-speed ALU can perform three binary arithmetic and five logic operations on the two 4-bit input words (R₃-R₀ and S₃-S₀). The R-input field is driven from a 2-input multiplexer, whereas the S-input field is driven by a 3-input multiplexer. Both the R- and S-multiplexers

have an inhibit capability, where no data is passed — this is equivalent to a "zero" source operand. Referring to figure 1, observe that the A-port output of the RAM and the 4-bit direct-data inputs (D₃-D₀) are connected to the R-input multiplexers; the S-input multiplexer has three inputs — one from the A-port of RAM, one from the B-port of RAM, and one from the Q-register.

With the foregoing input-multiplexer scheme, the inputs (A, B, D, Q, and "Zero"), when taken in pairs, provide any one of ten source operands for the ALU — AB, AD, AQ, A0, BD, BQ, B0, DQ, D0, and Q0. When the A and B address fields for RAM are identical, it is clear that certain combinations (AD/BD, AQ/BQ, and A0/B0) are redundant; that is, the identical function is implemented for either operand. Only seven of the combinations are completely nonredundant. Eight of the ten combinations (source operands) are implemented by the IDM2901A microprocessor. The ALU source operands are selected by three microinstruction inputs — I₀, I₁, and I₂. These inputs are defined in figure 2. Each of the preceding D and Q operands provides an essential function. The D input (direct-data) is used to load the working registers inside the 2901 device; also, this input source can be used to modify data files within the ALU. The Q-register is an internal 4-bit data source that is well suited for a multiply/divide operation; however, for some applications, it can be used as a data-holding register or as an accumulator.

The ALU is a high-speed arithmetic/logic operator that is capable of performing three binary arithmetic functions and five logic functions. Three microinstruction inputs (I₃, I₄, and I₅) are used to select one of the eight functions; these inputs, along with their octal codes, are defined in figure 3.

Micro Code				ALU Source Operands	
I ₂	I ₁	I ₀	Octal Code	R	S
L	L	L	0	A	Q
L	L	H	1	A	B
L	H	L	2	O	Q
L	H	H	3	O	B
H	L	L	4	O	A
H	L	H	5	D	A
H	H	L	6	D	Q
H	H	H	7	D	O

Figure 2. ALU Source Operand Control.

Micro Code				ALU Function	Symbol
I ₅	I ₄	I ₃	Octal Code		
L	L	L	0	R Plus S	R + S
L	L	H	1	S Minus R	S - R
L	H	L	2	R Minus S	R - S
L	H	H	3	R OR S	R V S
H	L	L	4	R AND S	R ∧ S
H	L	H	5	\bar{R} AND S	$\bar{R} \wedge S$
H	H	L	6	R EX-OR S	R ∨ S
H	H	H	7	R EX-NOR S	$\bar{R} \nabla S$

Figure 3. ALU Function Control

Normally, the look-ahead carry mode is used when cascading the ALUs of several microprocessor devices. The carry generate (\bar{G}) and carry propagate (\bar{P}) outputs are suitable for use in a carry-look-ahead generator. A carry-out (C_{n+4}) is also generated and is available for use as the carry flag in a status register or as a ripple-carry output. Both carry-in (C_n) and carry-out (C_{n+4}) are active-high signals. Three other status-oriented outputs are available from the ALU; these are F_3 , $F=0$, and overflow (OVR). The F_3 output is the most significant (sign) bit of the ALU, and, without enabling the TRI-STATE outputs, it can be used to determine positive or negative results. When enabled, the logic level of F_3 is identical to that of sign bit Y_3 . The $F=0$ output is used for zero detect; $F=0$ is high when, all F outputs are low. The $F=0$ output is of the open-collector type and can be wire ORed between microprocessor slices. The overflow (OVR) output is used to flag arithmetic operations that exceed the available twos-complement number range. When an overflow exists (C_{n+3} and C_{n+4} are of opposite polarity), the OVR output is high.

Outputs from the ALU can be stored in the register file or the Q register, or can be transmitted to the outside world. Eight possible destination codes are defined by microinstruction inputs I_6 , I_7 , and I_8 ; the various destination control codes are shown in figure 4. The 4-bit data field (Y_3-Y_0) is a TRI-STATE output that can be directly bus organized. The Y outputs are enabled by \bar{OE} ; when this control signal is high, the Y-outputs are TRI-STATEd. A 2-input multiplexer is also used at the Y-output port to select either the A port of RAM or the F output of the ALU; this selection is controlled by the previously described microinstruction inputs (I_6 , I_7 , and I_8).

As previously described, the RAM inputs (register file) are driven by a 3-input multiplexer. Thus, outputs from the ALU can be entered nonshifted, shifted up (towards MSB) one position ($\times 2$), or shifted down (towards LSB) one position ($\div 2$). The shifter is equipped with two ports — RAM₀ and RAM₃; both ports consist of a TRI-STATE buffer-driver, each of which supplies one input to the foregoing multiplexer. In the shift-up ($\times 2$) mode, the RAM₃ output driver and the RAM₀ multiplexer input are enabled, whereas in the shift-down ($\div 2$) mode, the RAM₀ output driver and RAM₃ multiplexer

input are enabled; in the no-shift mode, both drivers are TRI-STATE and neither multiplexer input is enabled. The shifter is controlled by the I_6 , I_7 , and I_8 microinstruction inputs.

The Q register likewise is driven from a 3-input multiplexer and the Q shifter is equipped with two input/output ports — Q₀ and Q₃. Operation of these two ports is similar to that of the RAM shifter, and the ports are controlled by I_6 , I_7 , and I_8 . In the shift-up or shift-down modes, the Q register is shifted in a specified direction with the input/output terminals of the register being an input (for a shift-up) or an output (for a shift-down). In the no-shift mode, the multiplexer may enter the ALU data into the Q register; in this case, input/output lines of the register are TRI-STATE.

The clock input shown in figure 1 controls the RAM, the A and B latches, and the Q register. When the clock input is high, the A and B latches are open and data from the RAM outputs is allowed to pass through to the ALU or "Y" outputs. When the clock input is low, both latches are closed and the last data entered is retained. When the clock input is low and if the input control code (I_6 , I_7 , and I_8) has enabled a file-write operation, new data, as defined by the 4-bit B-address field, is written into the RAM file. When enabled, data is clocked into the Q register on the low-to-high transition of the clock pulse.

Source Operands and ALU Functions

Any one of eight source operand pairs can be selected by instruction inputs I_0 , I_1 , and I_2 for use by the ALU; instruction inputs I_3 , I_4 , and I_5 then control function selection for the ALU — five logic and three arithmetic functions. In the arithmetic mode, the carry input (C_n) also affects the ALU functions; the carry input has no effect on the "F" result in the logic mode. These control parameters (I_6-I_0 and C_n) are summarized in figure 5 to completely define the ALU/source operand functions.

The ALU functions can also be examined on a task basis: that is, add, subtract, AND, OR, and so on. Again, in the arithmetic mode, the carry input will affect the result, whereas in the logic mode it will not. Figures 6 and 7, respectively, define the various logic and arithmetic functions of the ALU; both carry states ($C_n=0/C_n=1$) are defined in the function matrices.

Figure 4. ALU Destination Control

Micro Code				RAM Function		Q-Reg. Function		Y Output	RAM Shifter		Q Shifter	
I_8	I_7	I_6	Octal Code	Shift	Load	Shift	Load		RAM ₀	RAM ₃	Q ₀	Q ₃
L	L	L	0	X	None	None	F → Q	F	X	X	X	X
L	L	H	1	X	None	X	None	F	X	X	X	X
L	H	L	2	None	F → B	X	None	A	X	X	X	X
L	H	H	3	None	F → B	X	None	F	X	X	X	X
H	L	L	4	Down	F/2 → B	Down	Q/2 → Q	F	F ₀	IN ₃	Q ₀	IN ₃
H	L	H	5	Down	F/2 → B	X	None	F	F ₀	IN ₃	Q ₀	X
H	H	L	6	Up	2F → B	Up	2Q → Q	F	IN ₀	F ₃	IN ₀	Q ₃
H	H	H	7	Up	2F → B	X	None	F	IN ₀	F ₃	X	Q ₃

X = Don't care. Electrically, the shift pin is a TTL input internally connected to a TRI-STATE output which is in the high-impedance state.

B = Register Addressed by B inputs.

Up is toward MSB, Down is toward LSB.

Figure 5. Source Operand and ALU Function Matrix

		Figure 5. Source Operand and ALU Function Matrix								
		I _{2,1,0} Octal	0	1	2	3	4	5	6	7
Octal I _{5,4,3}	ALU Source	A, Q	A, B	O, Q	O, B	O, A	D, A	D, Q	D, O	
	ALU Function									
0	C _n = L R Plus S C _n = H	A + Q A + Q + 1	A + B A + B + 1	Q Q + 1	B B + 1	A A + 1	D + A D + A + 1	D + Q D + Q + 1	D D + 1	
1	C _n = L S Minus R C _n = H	Q - A - 1 Q - A	B - A - 1 B - A	Q - 1 Q	B - 1 B	A - 1 A	A - D - 1 A - D	Q - D - 1 Q - D	- D - 1 - D	
2	C _n = L R Minus S C _n = H	A - Q - 1 A - Q	A - B - 1 A - B	- Q - 1 - Q	- B - 1 - B	- A - 1 - A	D - A - 1 D - A	D - Q - 1 D - Q	D - 1 D	
3	R OR S	A V Q	A V B	Q	B	A	D V A	D V Q	D	
4	R AND S	A ∧ Q	A ∧ B	0	0	0	D ∧ A	D ∧ Q	0	
5	\bar{R} AND S	$\bar{A} \wedge Q$	$\bar{A} \wedge B$	Q	B	A	$\bar{D} \wedge A$	$\bar{D} \wedge Q$	0	
6	R EX-OR S	A ∨ Q	A ∨ B	Q	B	A	D ∨ A	D ∨ Q	D	
7	R EX-NOR S	$\overline{A \vee Q}$	$\overline{A \vee B}$	\bar{Q}	\bar{B}	\bar{A}	$\overline{D \vee A}$	$\overline{D \vee Q}$	\bar{D}	

+ = Plus; - = Minus; V = OR, ∧ = AND; ∨ = EX-OR.

Figure 6. ALU Logic Mode Functions (C_n Irrelevant)

Octal I _{5,4,3} /I _{2,1,0}	Group	Function
40 41 45 46	AND	A ∧ Q A ∧ B D ∧ A D ∧ Q
30 31 35 36	OR	A ∨ Q A ∨ B D ∨ A D ∨ Q
60 61 65 66	EX-OR	A ∨ Q A ∨ B D ∨ A D ∨ Q
70 71 75 76	EX-NOR	$\overline{A \vee Q}$ $\overline{A \vee B}$ $\overline{D \vee A}$ $\overline{D \vee Q}$
72 73 74 77	INVERT	\bar{Q} \bar{B} \bar{A} \bar{D}
62 63 64 67	PASS	Q B A D
32 33 34 37	PASS	Q B A D
42 43 44 47	"ZERO"	0 0 0 0
50 51 55 56	MASK	$\bar{A} \wedge Q$ $\bar{A} \wedge B$ $\bar{D} \wedge A$ $\bar{D} \wedge Q$

Figure 7. ALU Arithmetic Mode Functions

Octal I _{5,4,3} /I _{2,1,0}	C _n = 0 (Low)		C _n = 1 (High)	
	Group	Function	Group	Function
00 01 05 06	ADD	A + Q A + B D + A D + Q	ADD plus one	A + Q + 1 A + B + 1 D + A + 1 D + Q + 1
02 03 04 07	PASS	Q B A D	Increment	Q + 1 B + 1 A + 1 D + 1
12 13 14 27	Decrement	Q - 1 B - 1 A - 1 D - 1	PASS	Q B A D
22 23 24 17	1s Comp	- Q - 1 - B - 1 - A - 1 - D - 1	2s Comp (Negate)	- Q - B - A - D
10 11 15 16 20 21 25 26	Subtract (1s Comp)	Q - A - 1 B - A - 1 A - D - 1 Q - O - 1 A - Q - 1 A - B - 1 D - A - 1 D - Q - 1	Subtract (2s Comp)	Q - A B - A A - D Q - D A - Q A - B D - A D - Q

Pinout Descriptions of IDM2901

Pin functions for the IDM2901 4-bit slice microprocessor are as follows:

- A₃-A₀** 4-bit address field used to select one of the file registers whose contents are displayed through the A port of RAM.
- B₃-B₀** 4-bit address field used to select one of the file registers whose contents are displayed through the B port of RAM. When the clock is low, new data can be written into the selected B-port register.
- I₈-I₀** Nine instruction-control lines — I₀/I₁/I₂ determine data sources of ALU, I₃/I₄/I₅ select ALU function, and I₆/I₇/I₈ select data inputs for the Q register or the register file.
- Q₃/RAM₃** Serves as shift data input/output lines for the most significant bit (MSB) of Q register (Q₃) and the register stack (RAM₃). These lines are TRI-STATE outputs that connect to TTL inputs within the IDM2901 device. When the destination code, as defined by I₆/I₇/I₈, indicates an up-shift (octal 6 or 7), the TRI-STATE outputs are enabled; accordingly, the MSB of the Q register is available on the Q₃ pin and the MSB of the ALU output is available on the RAM₃ pin. Otherwise, these output lines are TRI-STATE or serve as LS-TTL inputs. When a down-shift is indicated by the destination code, the Q₃ and RAM₃ pins are used as data inputs to the MSB of the Q register or RAM.
- Q₀/RAM₀** These shift lines are similar to Q₃ and RAM₃, except they operate on the least significant bit (LSB) of the Q register and RAM. To transfer data for up- and down-shifts of the Q register and the ALU, the Q₀ and RAM₀ pins are connected, respectively, to the next less-significant device (Q_n and RAM_n) in the cascaded chain.
- D₃-D₀** A 4-bit data field that can be selected as a source of external data for ALU — D₀ is the least significant bit.
- Y₃-Y₀** 4-bit output data of IDM2901. These lines are TRI-STATE; when enabled, they provide either the ALU output or data from the A port of the register file — the selected source is determined by the destination code, as defined by I₆, I₇, and I₈.

- \overline{OE}** When the Output Enable (\overline{OE}) signal is high, the Y outputs are inactive; when the signal is active-low, the active high or low outputs are enabled.
- $\overline{P}/\overline{G}$** Carry generate and propagate outputs — see figure 8 for logic equations.
- OVR** The overflow flag corresponds to the exclusive-OR of the carry-in and carry-out of the MSB of the ALU. When set high, it indicates that the result of an arithmetic twos-complement operation has overflowed into the sign bit — see figure 8 for the logic equation.
- F = 0** An open-collector output that goes high if all data lines (F₃-F₀) are low, that is, the result of an ALU operation is zero.
- C_n** Carry-in to ALU.
- C_{n+4}** Carry-out of ALU — see figure 8 for logic equations.
- CP** Clock input. Outputs of Q register and file are clocked on low-to-high transition; the low interval of the clock input corresponds to the "write enable" period of the 16-by-4 RAM, that is, the "master" latches of the register file. When the clock is low, the output latches store the data previously held at the RAM outputs; thus, synchronous master-slave operation of the register file is permitted.
- F₃** Most significant (sign) bit output of the ALU.

Logic Functions for G, P, C_{n+4}, and OVR

When the IDM2901 is in the add or the subtract mode, four signals (G, P, C_{n+4}, and OVR) are available to indicate carry and overflow conditions. Based on the eight ALU functions, logic equations for these signal are shown in figure 8. (Note: The "R" and "S" inputs are selected according to figure 2.)

Definitions (+ = OR):

$$\begin{aligned}
 P_0 &= R_0 + S_0 & G_0 &= R_0 S_0 \\
 P_1 &= R_1 + S_1 & G_1 &= R_1 S_1 \\
 P_2 &= R_2 + S_2 & G_2 &= R_2 S_2 \\
 P_3 &= R_3 + S_3 & G_3 &= R_3 S_3
 \end{aligned}$$

$$\begin{aligned}
 C_4 &= G_3 + P_3 G_2 + P_3 P_2 G_1 + P_3 P_2 P_1 G_0 + P_3 P_2 P_1 P_0 C_n \\
 C_3 &= G_2 + P_2 G_1 + P_2 P_1 G_0 + P_2 P_1 P_0 C_n
 \end{aligned}$$

I _{5,4,3}	Function	\overline{P}	\overline{G}	C _{n+4}	OVR
0	R + S	$\overline{P_3 P_2 P_1 P_0}$	$G_3 + P_3 G_2 + P_3 P_2 G_1 + P_3 P_2 P_1 G_0$	C ₄	C ₃ ∨ C ₄
1	S - R	Same as R + S equations, but substitute \overline{R}_i for R _i in definitions.			
2	R - S	Same as R + S equations, but substitute \overline{S}_i for S _i in definitions.			
3	R ∨ S	LOW	$P_3 P_2 P_1 P_0$	$\overline{P_3 P_2 P_1 P_0} + C_n$	$\overline{P_3 P_2 P_1 P_0} + C_n$
4	R ∧ S	LOW	$G_3 + G_2 + G_1 + G_0$	$G_3 + G_2 + G_1 + G_0 + C_n$	$G_3 + G_2 + G_1 + G_0 + C_n$
5	$\overline{R} \wedge S$	LOW	Same as R ∧ S equations, but substitute \overline{R}_i for R _i in definitions.		
6	R ∨ \overline{S}	Same as R ∨ S equations, but substitute \overline{R}_i for R _i in definitions.			
7	$\overline{R} \vee \overline{S}$	$G_3 + G_2 + G_1 + G_0$	$G_3 + P_3 G_2 + P_3 P_2 G_1 + P_3 P_2 P_1 G_0$	See Note 1	See Note 2

Note 1: $G_3 + P_3 G_2 + P_3 P_2 G_1 + P_3 P_2 P_1 P_0 (G_0 + \overline{C}_n)$ Note 2: $(\overline{P_2} + \overline{G_2} P_1 + \overline{G_2} \overline{G_1} P_0 + \overline{G_2} \overline{G_1} \overline{G_0} C_n) \vee (P_3 + \overline{G_3} \overline{P_2} + \overline{G_3} \overline{G_2} P_1 + \overline{G_3} \overline{G_2} \overline{G_1} P_0 + \overline{G_3} \overline{G_2} \overline{G_1} \overline{G_0} C_n)$

Figure 8. Logic Equations for Flag Outputs

Guaranteed Operating Conditions Over Temperature and Voltage for IDM2901A

When operated in a system, the timing requirements for the IDM2901 are defined in tables 1, 2, and 3. Table 1 provides clock characteristics of the IDM2901, table 2 gives the combinational delay times from input to output, and table 3 specifies setup and hold times. If used according to the specified delay and setup times, the device is guaranteed to function properly over the entire operating range. Table 3 defines the time prior to the end of the cycle (low-to-high transition of clock pulse) that each input must be stable to guarantee that the correct data is written into one of the internal registers.

Table 1. Cycle Time and Clock Characteristics

Time	IDM2901A	
	JC, NC	JM, JM/883
Read-Modify-Write Cycle (time from selection of A, B registers to end of cycle)	60 ns	75 ns
Maximum Clock Frequency to Shift Q Register (50% duty cycle)	16 MHz	16 MHz
Minimum Clock Low Time	30 ns	30 ns
Minimum Clock High Time	30 ns	30 ns
Minimum Clock Period	60 ns	75 ns

Table 2. Maximum Combinational Propagation Delays (all in ns; $C_L < 50 \text{ pF}$)

To Output / From Input	Commercial IDM2901A JC, NC (0°C to +70°C; 5V ± 5%)							Military IDM2901A JM, JM/883 (-55°C to +125°C; 5V ± 10%)								
	Y	F ₃	C _{n+4}	G/P	F=0 R _L = 470	OVR	Shift Outputs		Y	F ₃	C _{n+4}	G/P	F=0 R _L = 470	OVR	Shift Outputs	
							RAM ₀ RAM ₃	Q ₀ Q ₃							RAM ₀ RAM ₃	Q ₀ Q ₃
A, B	65	65	65	60	70	65	70	-	80	80	80	65	85	80	80	-
D (arithmetic mode)	40	40	40	35	55	45	50	-	45	45	45	40	65	55	60	-
D (I = X37)	40	40	-	-	55	-	50	-	45	45	-	-	60	-	60	-
C _n	30	30	20	-	40	30	35	-	35	35	25	-	50	35	45	-
I _{2,1,0}	55	50	50	45	60	50	60	-	60	60	55	50	75	60	75	-
I _{5,4,3}	50	50	50	45	55	50	50	-	60	60	60	55	70	60	60	-
I _{8,7,6}	30	-	-	-	-	-	30	30	35	-	-	-	-	-	35	35
OE Enable/Disable	30/25	-	-	-	-	-	-	-	40/25	-	-	-	-	-	-	-
A Bypassing ALU (I = 2xx)	40	-	-	-	-	-	-	-	50	-	-	-	-	-	-	-
Clock (Note 6)	60	60	60	50	60	55	60	30	65	65	65	55	75	70	75	35

Table 3. Maximum Setup and Hold Times (all in ns) – Note 1

From Input	Notes	Commercial IDM2901A JC, NC (0°C to +70°C, 5V ± 5%)		Military IDM2901A JM, JM/883 (-55°C to +125°C, 5V ± 10%)	
		Setup Time	Hold Time	Setup Time	Hold Time
A, B Source	2, 3, 4, 5	60, t _{pwL} + 20	0	75, t _{pwL} + 25	0
B Destination	2, 4	t _{pwL} + 15	0	t _{pwL} + 15	0
D (arithmetic mode)		40	0	50	0
D (I = X37)	5	40	0	50	0
C _n		35	0	40	0
I _{2,1,0}		45	0	55	0
I _{5,4,3}		45	0	55	0
I _{8,7,6}	4	t _{pwL} + 15	0	t _{pwL} + 15	0
RAM _{0,3} /Q _{0,3}		20	0	25	0

Note 1: See figures 9 and 10.

Note 2: If the B address is used as a source operand, allow for the "A, B Source" setup time; if it is used only for the destination address, use the "B Destination" setup time.

Note 3: Where two numbers are shown, both must be met.

Note 4: "t_{pwL}" is the clock low time.

Note 5: DVO is the fastest way to load the RAM from the D inputs. This function is obtained with I = X37.

Note 6: Using Q register as source operand in arithmetic mode. Clock is not normally in critical speed path when Q is not a source.

Guaranteed Operating Conditions Over Temperature and Voltage for IDM2901A-1

When operated in a system, the timing requirements for the IDM2901A-1 are defined in tables 1, 2, and 3. Table 1 provides clock characteristics of the IDM2901A-1, table 2 gives the combinational delay times from input to output, and table 3 specifies setup and hold times. If used according to the specified delay and setup times, the device is guaranteed to function properly over the entire operating range. Table 3 defines the time prior to the end of the cycle (low-to-high transition of clock pulse) that each input must be stable to guarantee that the correct data is written into one of the internal registers.

Table 1. Cycle Time and Clock Characteristics

Time	IDM2901A-1	
	JC, NC	JM, JM/883
Read-Modify-Write Cycle (time from selection of A, B registers to end of cycle)	60 ns	75 ns
Maximum Clock Frequency to Shift Q Register (50% duty cycle)	16 MHz	16 MHz
Minimum Clock Low Time	30 ns	30 ns
Minimum Clock High Time	30 ns	30 ns
Minimum Clock Period	60 ns	75 ns

Table 2. Maximum Combinational Propagation Delays
(all in ns; $C_L < 50$ pF)

To Output From Input	Commercial IDM2901A-1 JC, NC (0°C to +70°C; 5V ± 5%)							Military IDM2901A-1 JM, JM/883 (-55°C to +125°C; 5V ± 10%)								
	Y	F ₃	C _{n+4}	$\overline{G/P}$	F=0 R _L = 470	OVR	Shift Outputs		Y	F ₃	C _{n+4}	$\overline{G/P}$	F=0 R _L = 470	OVR	Shift Outputs	
							RAM ₀ RAM ₃	Q ₀ Q ₃							RAM ₀ RAM ₃	Q ₀ Q ₃
A, B	50	50	50	45	55	60	55	—	60	60	60	60	65	75	65	—
D (arithmetic mode)	32	32	32	30	32	40	35	—	40	40	40	40	40	50	45	—
D (I = X37)	32	32	—	—	32	—	35	—	40	40	—	—	40	—	45	—
C _n	25	22	16	—	30	25	35	—	32	30	20	—	40	35	45	—
I _{2,1,0}	40	35	35	30	40	45	45	—	50	45	45	40	50	55	55	—
I _{5,4,3}	35	35	35	32	40	45	45	—	45	45	45	40	50	55	55	—
I _{8,7,6}	25	—	—	—	—	—	30	30	35	—	—	—	—	—	35	35
\overline{OE} Enable/Disable	20/20	—	—	—	—	—	—	—	25/25	—	—	—	—	—	—	—
A Bypassing ALU (I = 2xx)	40	—	—	—	—	—	—	—	50	—	—	—	—	—	—	—
Clock \downarrow (Note 6)	50	45	45	40	50	55	55	30	60	55	55	50	60	65	65	35

Table 3. Maximum Setup and Hold Times (all in ns) — Note 1

From Input	Notes	Commercial IDM2901A-1 JC, NC (0°C to +70°C, 5V ± 5%)		Military IDM2901A-1 JM, JM/883 (-55°C to +125°C, 5V ± 10%)	
		Setup Time	Hold Time	Setup Time	Hold Time
A, B Source	2, 3, 4, 5	60, t _{pwL} + 20	0	75, t _{pwL} + 25	0
B Destination	2, 4	t _{pwL} + 15	0	t _{pwL} + 15	0
D (arithmetic mode)		40	0	50	0
D (I = X37)	5	40	0	50	0
C _n		35	0	40	0
I _{2,1,0}		45	0	55	0
I _{5,4,3}		45	0	55	0
I _{8,7,6}	4	t _{pwL} + 15	0	t _{pwL} + 15	0
RAM _{0,3} /Q _{0,3}		15/10	0	25/15	0

Note 1: See figures 9 and 10.

Note 2: If the B address is used as a source operand, allow for the "A, B Source" setup time; if it is used only for the destination address, use the "B Destination" setup time.

Note 3: Where two numbers are shown, both must be met.

Note 4: "t_{pwL}" is the clock low time.

Note 5: DVO is the fastest way to load the RAM from the D inputs. This function is obtained with I = X37.

Note 6: Using Q register as source operand in arithmetic mode. Clock is not normally in critical speed path when Q is not a source.

Guaranteed Operating Conditions Over Temperature and Voltage for IDM2901A-2

When operated in a system, the timing requirements for the IDM2901A-2 are defined in tables 1, 2, and 3. Table 1 provides clock characteristics of the IDM2901A-2, table 2 gives the combinational delay times from input to output, and table 3 specifies setup and hold times. If used according to the specified delay and setup times, the device is guaranteed to function properly over the entire operating range. Table 3 defines the time prior to the end of the cycle (low-to-high transition of clock pulse) that each input must be stable to guarantee that the correct data is written into one of the internal registers.

TABLE 1. Cycle Time and Clock Characteristics

Time	IDM2901A-2	
	JC, NC	JM, JM/883
Read-Modify-Write Cycle (time from selection of A, B registers to end of cycle)	50 ns	65 ns
Maximum Clock Frequency to Shift Q Register (50% duty cycle)	20 MHz	16 MHz
Minimum Clock Low Time	25 ns	30 ns
Minimum Clock High Time	25 ns	30 ns
Minimum Clock Period	50 ns	65 ns

TABLE 2. Maximum Combinational Propagation Delays (all in ns; C_L 50pF)

to Output from Input	Commercial IDM2901A-2 JC, NC (0°C to +70°C; 5V ± 5%)							Military IDM2901A-2 JM, JM/883 (-55°C to +125°C; 5V ± 10%)										
	Y	F ₃	C _{n+4}	G/P	F=0 R _L = 470	OVR	Shift Outputs			Y	F ₃	C _{n+4}	G/P	F=0 R _L = 470	OVR	Shift Outputs		
							RAM ₀	Q ₀	Q ₃							RAM ₀	Q ₀	Q ₃
A, B	44	44	44	35	44	45	40	—	55	50	50	45	55	55	50	—		
D (arithmetic mode)	28	28	28	25	31	34	30	—	37	37	37	34	40	40	37	—		
D (I = X37)	28	28	—	—	31	—	30	—	37	37	—	—	40	—	37	—		
C _n	25	22	16	—	25	25	25	—	30	25	19	—	33	30	30	—		
I _{2,1,0}	35	35	35	28	35	39	35	—	45	45	45	45	45	45	40	—		
I _{5,4,3}	35	35	35	32	35	35	35	—	45	40	40	40	45	45	40	—		
I _{8,7,6}	25	—	—	—	—	—	30	30	30	—	—	—	—	—	35	35		
OE Enable/Disable	20/20	—	—	—	—	—	—	—	25/25	—	—	—	—	—	—	—		
A Bypassing ALU (I = 2xx)	35	—	—	—	—	—	—	—	45	—	—	—	—	—	—	—		
Clock (Note 6)	40	40	40	40	40	45	45	28	50	45	45	40	55	50	50	30		

TABLE 3. Maximum Setup and Hold Times (all in ns) — Note 1

From Input	Notes	Commercial IDM2901A-2 JC, NC (0°C to +70°C, 5V ± 5%)		Military IDM2901A-2 JM, JM/883 (-55°C to +125°C, 5V ± 10%)	
		Setup Time	Hold Time	Setup Time	Hold Time
A, B Source	2, 3, 4, 5	50, t _{pwL} + 20	0	60, t _{pwL} + 20	0
B Destination	2, 4	t _{pwL} + 15	0	t _{pwL} + 15	0
D (arithmetic mode)		35	0	40	0
D (I = X37)	5	35	0	40	0
C _n		26	0	30	0
I _{2,1,0}		35	0	45	0
I _{5,4,3}		30	0	45	0
I _{8,7,6}	4	t _{pwL} + 10	0	t _{pwL} + 14	0
RAM _{0,3} /Q _{0,3}		12/10	0	15/15	0

Note 1: See figures 9 and 10.

Note 2: If the B address is used as a source operand, allow for the "A, B Source" setup time; if it is used only for the destination address, use the "B Destination" setup time.

Note 3: Where two numbers are shown, both must be met.

Note 4: "t_{pwL}" is the clock low time.

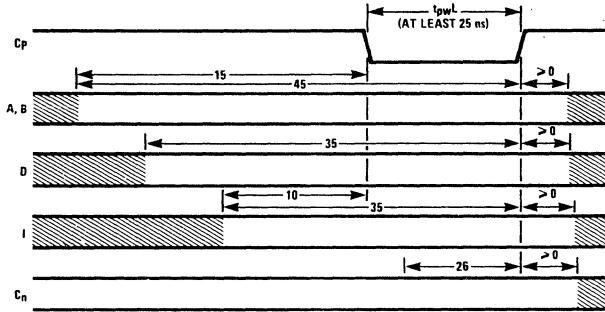
Note 5: DVO is the fastest way to load the RAM from the D inputs. This function is obtained with I = X37.

Note 6: Using Q register as source operand in arithmetic mode. Clock is not normally in critical speed path when Q is not a source.

Set-Up and Hold Times (minimum cycles from each input)

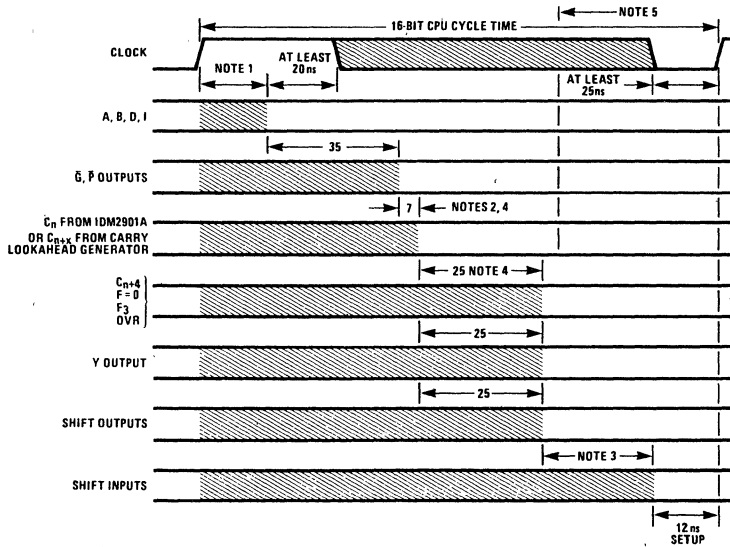
Setup and hold times are defined relative to the low-to-high transition of the clock pulse. At all times, inputs must be stable from the setup time prior to the clock until the hold time after the clock — observe that all

hold times are "zero." The set-up times allow sufficient time to perform the correct operation on the correct data so that the correct ALU data can be written into the correct register.



Note: Numbers shown are minimum data-stable times in nanoseconds for commercial product — see table 3 for detailed information.

Figure 9. Setup Times for Input Parameters of IDM2901



Notes:

1. This delay is the max t_{pd} of the register containing A, B, D, and I.
2. 7 ns for look-ahead carry. For ripple carry over 16 bits use $2 \times (C_n \rightarrow C_{n+4})$, or 24 ns.
3. This is the delay associated with the multiplexer between the shift outputs and the shift inputs on the IDM2901.
4. Not applicable for logic operations.
5. Clock rising edge may occur here if add and shift do not occur on same cycle.

Figure 10. Switching Waveforms for 16-Bit System Assuming A, B, D, and I are Driven from Registers with the Same Propagation Delay and Clocked by the IDM2901. (These are maximum times in nanoseconds using commercial product specifications.)

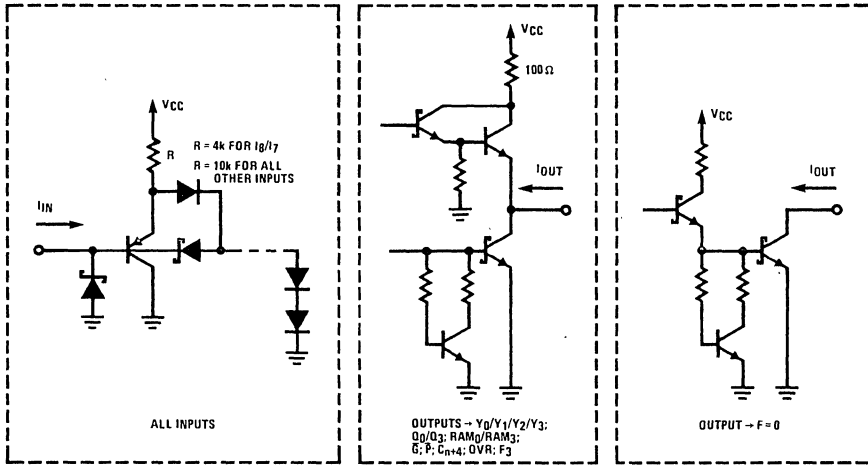
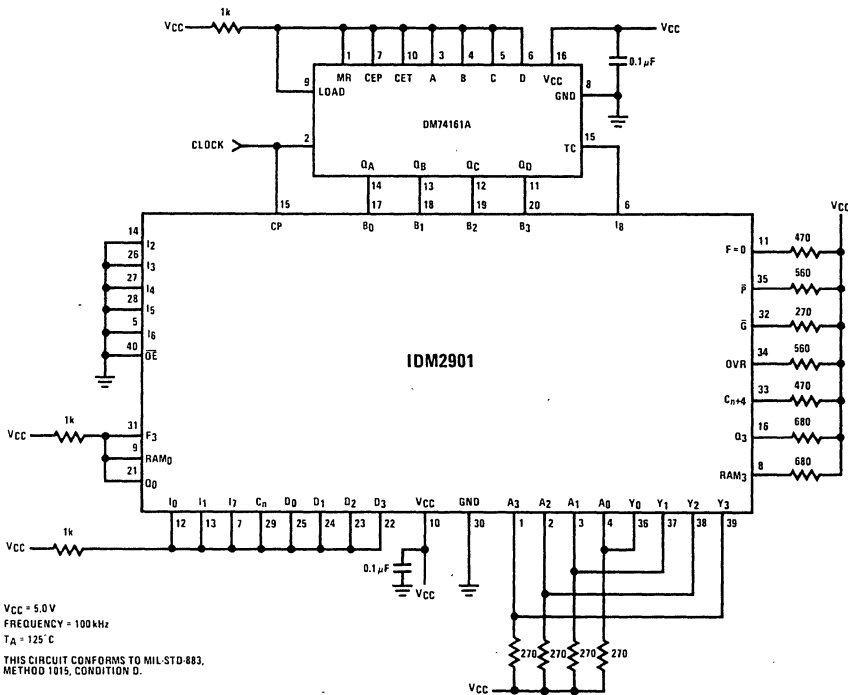


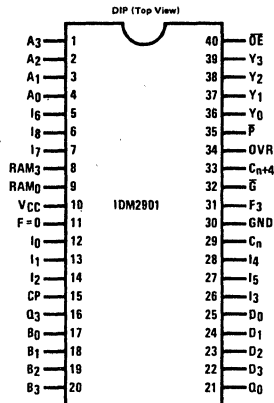
Figure 11. Equivalent Input/Output Current Interface Conditions for IDM2901



VCC = 5.0V
 FREQUENCY = 100kHz
 TA = 125°C
 THIS CIRCUIT CONFORMS TO MIL-STD-883,
 METHOD 1015, CONDITION D.

Figure 12. Burn-In Circuit for IDM2901

Connection Diagram



NOTE: PIN 1 IS MARKED FOR ORIENTATION.

Ordering Information

Package Type	Package Number	Temperature Range	Order Number
Molded DIP	N40A	0°C to +70°C	IDM2901ANC/IDM2901A-1NC/IDM2901A-2NC
Hermetic DIP	D40C	0°C to +70°C	IDM2901AJC/IDM2901A-1JC/IDM2901A-2JC
Hermetic DIP	D40C	-55°C to +125°C	IDM2901AJM/IDM2901A-1JM/IDM2901A-2JM
Hermetic DIP	D40C	-55°C to +125°C	IDM2901AJM/883/IDM2901A-1JM/883/IDM2901A-2JM/883

IDM2902 Look-Ahead Carry Generator

General Description

This circuit is a high-speed, look-ahead carry generator, capable of anticipating a carry across four binary adders or groups of adders. It is cascadable to perform full look-ahead across n-bit adders. Carry, generate-carry, and propagate-carry functions are provided as shown in the pin designation table.

When used in conjunction with the IDM2901A arithmetic logic units, this generator provides high-speed carry look-ahead capability for any word length. The IDM2902 generates the look-ahead (anticipated carry) across a group of four ALUs and, in addition, other carry look-ahead circuits may be employed to anticipate carry across sections of four look-ahead packages up to n bits. The method of cascading circuits to perform multi-level look-ahead is illustrated under typical application data.

Carry input and output of the ALUs are in their true form, and the carry propagate (P) and carry generate (G) are in negated form; therefore, the carry functions (inputs, outputs, generate, and propagate) of the look-

ahead generators are implemented in the compatible forms for direct connection to the ALU. Reinterpretations of carry functions, as explained on the IDM2901A data sheet, are also applicable to and compatible with the look-ahead generator. Positive logic equations for the 2902 parts are:

$$C_{n+x} = G_0 + P_0 C_n$$

$$C_{n+y} = G_1 + P_1 G_0 + P_1 P_0 C_n$$

$$C_{n+z} = G_2 + P_2 G_1 + P_2 P_1 G_0 + P_2 P_1 P_0 C_n$$

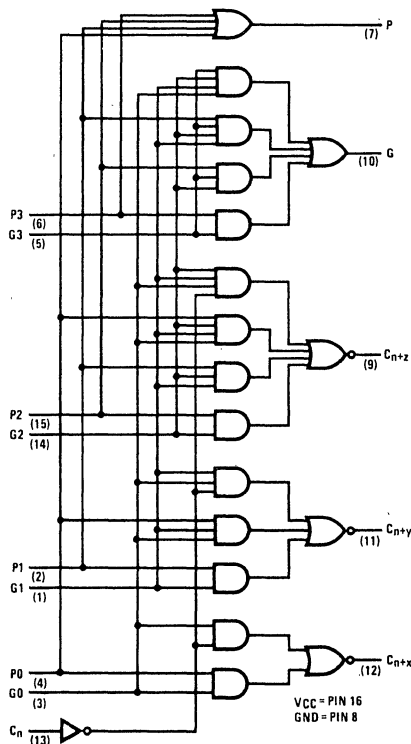
$$G = G_3 (P_3 + G_2) (P_3 + P_2 + G_1) (P_3 + P_2 + P_1 + G_0)$$

$$P = P_3 P_2 P_1 P_0$$

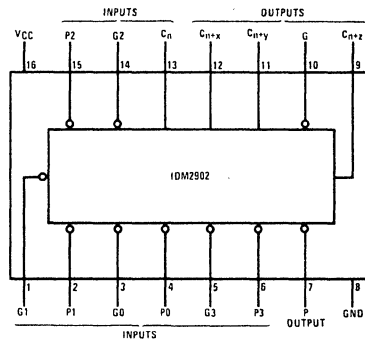
Features and Benefits

Type	Typical Propagation Delay Time	Typical Power Dissipation
IDM2902	7 ns	260 mW

Logic and Connection Diagram



Connection Diagram



Pin Designations

Designation	Pin Nos.	Function
G ₀ , G ₁ , G ₂ , G ₃	3, 1, 14, 5	Active Low Carry Generate Inputs
P ₀ , P ₁ , P ₂ , P ₃	4, 2, 15, 6	Active Low Carry Propagate Inputs
C _n	13	Carry Input
C _{n+x} , C _{n+y} , C _{n+z}	12, 11, 9	Carry Outputs
G	10	Active Low Carry Generate Output
P	7	Active Low Carry Propagate Output
V _{CC}	16	Supply Voltage
GND	8	Ground

Absolute Maximum Ratings

Storage Temperature	-65°C to +150°C
Temperature (Ambient) Under Bias	-55°C to +125°C
Supply Voltage to Ground Potential	-0.5 V to +6.3 V
DC Voltage Applied to Outputs for High Output State	-0.5 V to +V _{CC} max
DC Input Voltage	-0.5 V to +5.5 V
DC Output Current, into Outputs	30 mA
DC Input Current	-30 mA to +5.0 mA

Operating Range

P/N	Ambient Temperature	V _{CC}
IDM2902JC, NC	0°C to +70°C	4.75 V to 5.25 V
IDM2902JM, JM/883	-55°C to +125°C	4.50 V to 5.50 V

Electrical Characteristics Over Operating Temperature Range (unless otherwise noted)

Commercial	T _A = 0°C to +70°C	V _{CC} = 5.0 V ± 5%	MIN = 4.75 V	MAX = 5.25 V
Military	T _A = -55°C to +125°C	V _{CC} = 5.0 V ± 10%	MIN = 4.50 V	MAX = 5.50 V

Parameter	Description	Test Conditions (Note 1)	Typ. (Note 2)		Units	
			Min.	Max.		
V _{OH}	Output HIGH Voltage	V _{CC} = MIN, I _{OH} = -0.8 mA V _{IN} = V _{IH} or V _{IL}	2.7	3.4	V	
V _{OL}	Output LOW Voltage	V _{CC} = MIN, I _{OL} = 16 mA V _{IN} = V _{IH} or V _{IL}		0.5	V	
V _{IH}	Input HIGH Level	Guaranteed input logical HIGH voltage for all inputs	2.0		V	
V _{IL}	Input LOW Level	Guaranteed input logical LOW voltage for all inputs		0.8	V	
V _I	Input Clamp Voltage	V _{CC} = MIN, I _{IN} = -12 mA		-1.5	V	
I _{IL} (Note 3)	Input LOW Current	V _{CC} = MAX, V _{IN} = 0.5 V	C _n		-2	mA
			P ₃		-4	
			P ₂		-6	
			P ₀ , P ₁ , G ₃		-8.0	
			G ₀ , G ₂		-14	
			G ₁		-16	
I _{IH} (Note 3)	Input HIGH Current	V _{CC} = MAX, V _{IN} = 2.7 V	C _n		50	μA
			P ₃		100	
			P ₂		150	
			P ₀ , P ₁ , G ₃		200	
			G ₀ , G ₂		350	
			G ₁		400	
I _I	Input HIGH Current	V _{CC} = MAX, V _{IN} = 5.5 V			1.0	mA
I _{SC}	Output Short Circuit (Note 4)	V _{CC} = MAX, V _{OUT} = 0.0 V	-40		-100	mA
I _{CC}	Power Supply Current	V _{CC} = MAX All Outputs LOW	MIL	62	99	mA
			COM'L	58	94	
		V _{CC} = MAX All Outputs HIGH	MIL	37		mA
			COM'L	35		

Notes:

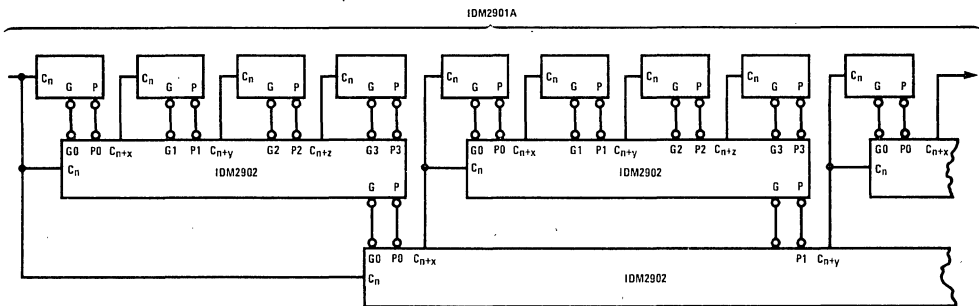
- For conditions shown as MIN or MAX, use the appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical limits are at V_{CC} = 5.0 V, 25°C ambient and maximum loading.
- Actual input currents = Unit Load Current times Input Load Factor (see Loading Rules).
- Not more than one output should be shorted at a time. Duration of the short circuit test should not exceed one second.

Switching Characteristics $V_{CC} = 5.0V, T_A = 25^\circ C, C_L = 15 pF, R_L = 400 \Omega$

Parameter	From (Input)	To (Output)	Test Conditions	Min.	Typ.	Max.	Units
tPLH	C _n	C _{n+j}	P ₀ = P ₁ = P ₂ = 0V G ₀ = G ₁ = G ₂ = 4.5V		9.0	12	ns
tPHL					9.0	12	
tPLH	P _i	C _{n+j}	P _i = 0V (j > i) C _n = G ₀ = G ₁ = G ₂ = 4.5V		6.0	8.0	ns
tPHL					6.0	8.0	
tPLH	G _i	C _{n+j}	G _i = 0V (j > i) C _n = P ₀ = P ₁ = P ₂ = 4.5V		7.0	10	ns
tPHL					7.0	10	
tPLH	P _i	G or P	P _i = 0V (j > i) C _n = G ₀ = G ₁ = G ₂ = 4.5V		6.0	10	ns
tPHL					6.0	10	
tPLH	G _i	G or P	G _i = 0V (j > i) C _n = P ₀ = P ₁ = P ₂ = 4.5V		7.0	10	ns
tPHL					7.0	10	

Typical Application

64-Bit ALU with Full Look-Ahead Carry in Three Levels



A AND B INPUTS AND F OUTPUTS ARE NOT SHOWN.

Ordering Information

Package Type	Package Number	Temperature Range	Order Number
Molded DIP	N16A	0°C to +70°C	IDM2902NC/DM74S182N
Hermetic DIP	J16A (D16C)	0°C to +70°C	IDM2902JC/DM74S182J
Hermetic DIP	J16A (D16C)	-55°C to +125°C	IDM2902JM/DM54S182J
Hermetic DIP	J16A (D16C)	-55°C to +125°C	IDM2902JM/883/DM54S182J/883

IDM2909A/11A Microprogram Sequencer

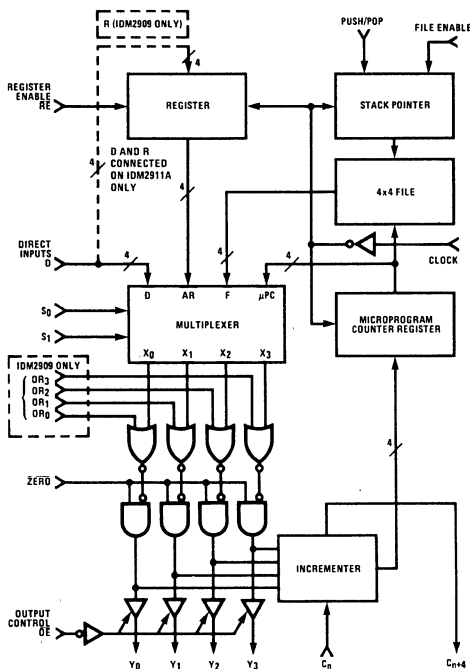
General Description

The IDM2909A is a 4-bit wide address controller that is used to sequence through a series of microinstructions contained in ROM or PROM. Two devices can be interconnected to generate an 8-bit address (256 words), three devices for a 12-bit address (4k words), and so on. For a given device, the 4-bit address field can originate from any one of four sources. These are: (1) direct "D" inputs from an external source, (2) external data from an internal register "R," (3) a push/pop stack that is 4 words deep, and (4) a program counter, which usually contains the last address incremented by "1." Control of the push/pop stack is such that the stack can efficiently execute nested subroutine linkages. Moreover, each of the four TRI-STATE outputs can be ORed with an external input to implement conditional skips or branch instructions; a separate line is used to force the outputs to an "all-zero" state. As shown in the block diagram, the IDM2911A is identical to the IDM2909A, except the four OR inputs are removed and the "D" and "R" inputs are connected. The IDM2909A is housed in a 28-pin dual-in-line package, whereas the IDM2911A is a 20-pin device.

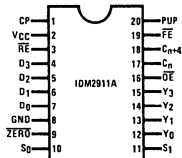
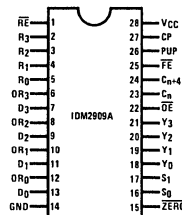
Features and Benefits

- 4-bit cascadable slice — any number of microwords can be generated.
- Internal address register — provides four address sources.
- Branch input for N-way branches — where "N" is any word in the microcode.
- Cascadable 4-bit microprogram counter.
- 4x4 file with stack pointer and push/pop control — four microsubroutines can be nested.
- Zero input for returning to microcode word "zero."
- Individual OR input for each bit to branch to higher microinstruction (IDM2909A only).
- TRI-STATE outputs.
- All internal registers change state on Low-to-High transition of clock pulse.

Simplified Block Diagram



Connection Diagrams



Absolute Maximum Ratings

Storage Temperature	-65°C to +150°C
Temperature (Ambient) Under Bias	-55°C to +125°C
Supply Voltage to Ground Potential Continuous	-0.5V to +7.0V
DC Voltage Applied to Outputs for High Output State	-0.5V to +V _{CC} max
DC Input Voltage	-0.5V to +7.0V
DC Output Current into Outputs	30 mA
DC Input Current	-30 mA to +5.0 mA

Operating Range

P/N	Ambient Temperature	V _{CC}
IDM2909ANC, JC	0°C to +70°C	4.75V to 5.25V
IDM2911ANC, JC	0°C to +70°C	4.75V to 5.25V
IDM2909AJM, JM/883	-55°C to +125°C	4.50V to 5.50V
IDM2911AJM, JM/883	-55°C to +125°C	4.50V to 5.50V

Electrical Characteristics

Commercial T_A = 0°C to +70°C, V_{CC} = 4.75V to 5.25V

Military T_A = -55°C to +125°C, V_{CC} = 4.50V to 5.50V

Parameter	Description	Test Conditions (Note 1)		Min.	Typ. (Note 2)	Max.	Units
V _{OH}	Output High Voltage	V _{CC} = min, V _{IN} = V _{IH} or V _{IL}	Mil	I _{OH} = -1.0 mA	2.4		V
			Com'l	I _{OH} = -2.6 mA	2.4		
V _{OL}	Output Low Voltage	V _{CC} = min, V _{IN} = V _{IH} or V _{IL}	I _{OL} = 4.0 mA			0.4	V
			I _{OL} = 8.0 mA			0.45	
			I _{OL} = 16 mA (Note 5)			0.5	
V _{IH}	Input High Level	Guaranteed input logical high voltage for all inputs		2.0			V
V _{IL}	Input Low Level	Guaranteed input logical low voltage for all inputs				0.8	V
V _I	Input Clamp Voltage	V _{CC} = min, I _{IN} = -18 mA				-1.5	V
I _{IL}	Input Low Current	V _{CC} = max, V _{IN} = 0.4 V				-0.36	mA
I _{IH}	Input High Current	V _{CC} = max, V _{IN} = 2.7 V				20	μA
I _I	Input High Current	V _{CC} = max, V _{IN} = 7.0 V				0.1	mA
I _{OS}	Output Short Circuit Current (Note 3)	V _{CC} = max		-40		-100	mA
I _{CC}	Power Supply Current	V _{CC} = max (Note 4)			80	130	mA
I _{OZL}	Output Off Current	V _{CC} = max, OE = 2.7 V	V _{OUT} = 0.4 V			-20	μA
			V _{OUT} = 2.7 V			20	

Notes:

- For conditions shown as MIN or MAX, use the appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical limits are at V_{CC} = 5.0V, 25°C ambient and maximum loading.
- Not more than one output should be shorted at a time. Duration of the short circuit test should not exceed one second.
- Apply GND to C_n, R₀, R₁, R₂, R₃, OR₀, OR₁, OR₂, OR₃, D₀, D₁, D₂, and D₃. Other inputs open. All outputs open. Measured after a LOW-to-HIGH clock transition.
- The 16 mA guarantee applies only to Y₀, Y₁, Y₂, and Y₃.

Standard Screening (Conforms to MIL-STD-883 for Class C Parts)

Step	MIL-STD-883 Method	Conditions	Level	
			IDM2909A/2911A NC, JC	IDM2909A/2911A JM
Pre-Seal Visual Inspection	2010	B	100%	100%
Stabilization Bake	1008	C 24-hour, 150°C	100%	100%
Temperature Cycle	1010	C -65°C to +150°C 10 cycles	100%	100%
Centrifuge	2001	B 10,000 G	100%*	100%
Fine Leak	1014	A 5×10^{-8} atm-cc/cm ³	100%*	100%
Gross Leak	1014	C Fluorocarbon	100%*	100%
Electrical Test Subgroups 1, 7, and 9	5004	See below for definitions of subgroups	100%	100%

Insert Additional Screening here for Class B Parts

Group A Sample Tests	5005	See below for definitions of subgroups		
Subgroup 1			LTPD = 5	LTPD = 5
Subgroup 2			LTPD = 7	LTPD = 7
Subgroup 3			LTPD = 7	LTPD = 7
Subgroup 7			LTPD = 7	LTPD = 5
Subgroup 8			LTPD = 7	LTPD = 7
Subgroup 9			LTPD = 7	LTPD = 5

*Not applicable to IDM2909ANC or IDM2911ANC.

Group A Subgroups
(as defined in MIL-STD-883, Method 5005)

Subgroup	Parameter	Temperature
1	DC	25°C
2	DC	Maximum Rated Temperature
3	DC	Minimum Rated Temperature
7	Function	25°C
8	Function	Maximum and Minimum Rated Temperature
9	Switching	25°C
10	Switching	Maximum Rated Temperature
11	Switching	Minimum Rated Temperature

Additional Screening for Class B Parts

Step	MIL-STD-883 Method	Conditions	Level
			IDM2909A/11A JM/883
Burn-In	1015	D 125°C 160 hours min.	100%
Electrical Test Subgroup 1	5004		100%
Subgroup 2			100%
Subgroup 3			100%
Subgroup 7			100%
Subgroup 9			100%
Return to Group A Tests in Standard Screening			

Switching Characteristics Over Operating Range

All parameters are guaranteed worst case over the operating voltage and temperature range for the device type.

IDM2909A/11A JC, NC $T_A = 0^\circ\text{C}$ to $+70^\circ\text{C}$ $V_{CC} = 4.75\text{V}$ to 5.25V

IDM2909A/11A JM, JM/883 $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$ $V_{CC} = 4.5\text{V}$ to 5.5V

Table 1. Minimum Clock Requirements

Minimum Clock Low Time	30
Minimum Clock High Time	30

Table 2.
Maximum Combinatorial Propagation Delays

Inputs	Outputs	
	Y_i	C_{n+4}
\overline{OE}	25	—
\overline{ZERO}	30	35
OR_i	20	30
S_0, S_1	30	35
D_i	20	30
C_n	—	18

Table 3. Maximum Delays from Clock to Outputs

Functional Path	Grade	Clock to Y_i	Clock to C_{n+4}
Register ($S_1 S_0 = LH$)	C	40	45
	M	50	55
μ Program Counter ($S_1 S_0 = LL$)	C	40	45
	M	50	55
File ($S_1 S_0 = HL$)	C	45	50
	M	55	60

$C_L \leq 50\text{pF}$
(except output disable tests)

Table 4.
Setup and Hold Time Requirements

External Inputs	t_s	t_h
\overline{RE}	20	0
R_i	15	0
PUSH/POP	20	0
\overline{FE}	20	0
C_n	15	0
D_i	20	0
OR_i	20	0
S_0, S_1	30	0
\overline{ZERO}	30	0

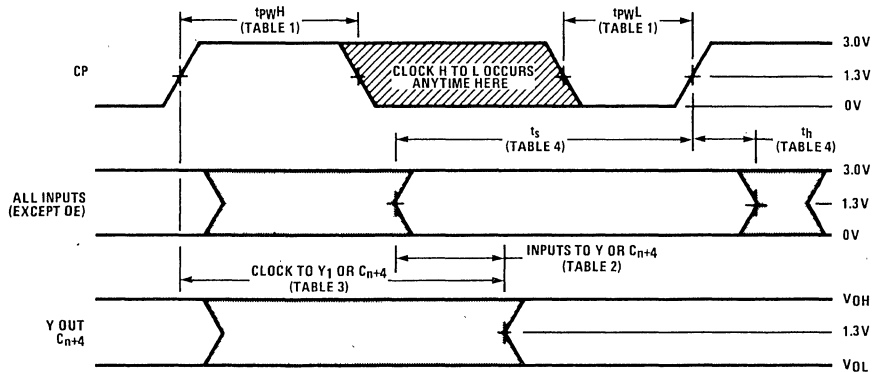


Figure 1. Switching Waveforms (refer to preceding tables for specific values)

Architecture of Microprogram Sequencer

A 4-input multiplexer selects one of four sources for the address of the next microinstruction address; these sources are: the address register, the microprogram counter, direct inputs, and the memory file. The multiplexer is controlled by the S_0/S_1 inputs. As shown in figure 2, the address register consists of four D-type edge-triggered flip-flops with a common clock enable. When the REGISTER ENABLE signal is low, new data is entered on the low-to-high transition of the clock. The "Q" outputs of the address register are available at the input of the multiplexer as a source for the next microinstruction address. The direct inputs (D_0 - D_3) can likewise be selected as an address input to the multiplexer.

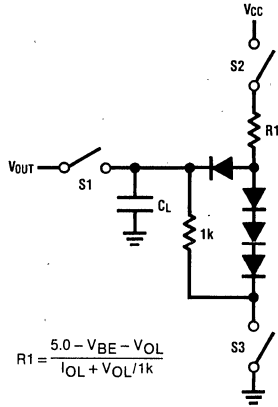
Both the IDM2909A and the IDM2911A are bipolar microprogram sequencers designed for use in high-speed

microprocessors, high-performance computer control units, and other applications where overlap fetch of the microinstruction is required. Each device is cascadable in 4-bit increments such that two devices can address up to 256 words of microprogram memory, three devices up to 4k of memory, and so on. A detailed block diagram of the microprogram sequencer is shown in figure 2.

In the IDM2911A, the 4-bit direct field is also used as an input to the address register, that is, R_0 and D_0 are connected, R_1 and D_1 are connected, and so on. With the "R" and "D" connections made and the OR inputs removed, the IDM2911A can perform an N-way branch, where "N" is any word in the microcode.

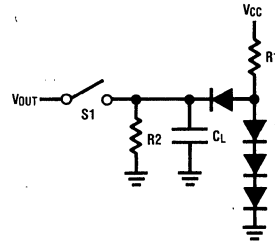
Test Output Load Configurations for IDM2909A/2911A

A. Three-State Outputs



$$R1 = \frac{5.0 - V_{BE} - V_{OL}}{I_{OL} + V_{OL}/1k}$$

B. Normal Outputs



$$R2 = \frac{2.4V}{I_{OH}}$$

$$R1 = \frac{5.0 - V_{BE} - V_{OL}}{I_{OL} + V_{OL}/R2}$$

Note 1: $C_L = 50$ pF includes scope probe, wiring and stray capacitances without device in test fixture.

Note 2: S1, S2, S3 are closed during function tests and all AC tests except output enable tests.

Note 3: S1 and S3 are closed while S2 is open for tp_{ZH} test.
S1 and S2 are closed while S3 is open for tp_{ZL} test.

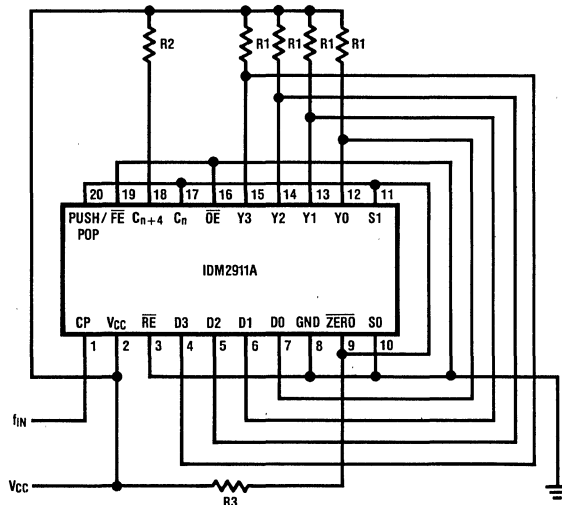
Note 4: $C_L = 5.0$ pF for output disable tests.

Test Output Loads

Pin # (DIP)	Pin Label	Test Circuit	IDM2909		IDM2909A	
			R1	R2	R1	R2
18-21	Y_{0-3}	A	300	1k	220	1k
24	C_{n+4}	B	470	2.4k	220	2.4k

Pin # (DIP)	Pin Label	Test Circuit	IDM2911		IDM2911A	
			R1	R2	R1	R2
12-15	Y_{0-3}	A	300	1k	220	1k
18	C_{n+4}	B	470	2.4k	220	2.4k

Burn-in Circuit for IDM2911A



Notes:

Max $I_{CC} = 200$ mA

$T_A = +125^\circ C$

Resistors = $\pm 5\%$

$R1 = 390\Omega$

$R2 = 560\Omega$

$R3 = 1k\Omega$

$f_{IN} = 100$ kHz, 50% duty cycle, 0V-3V

From clock buffer on each board:

$V_{CC} \text{ min} = 5.0V$

$V_{CC} \text{ max} = 5.1V$

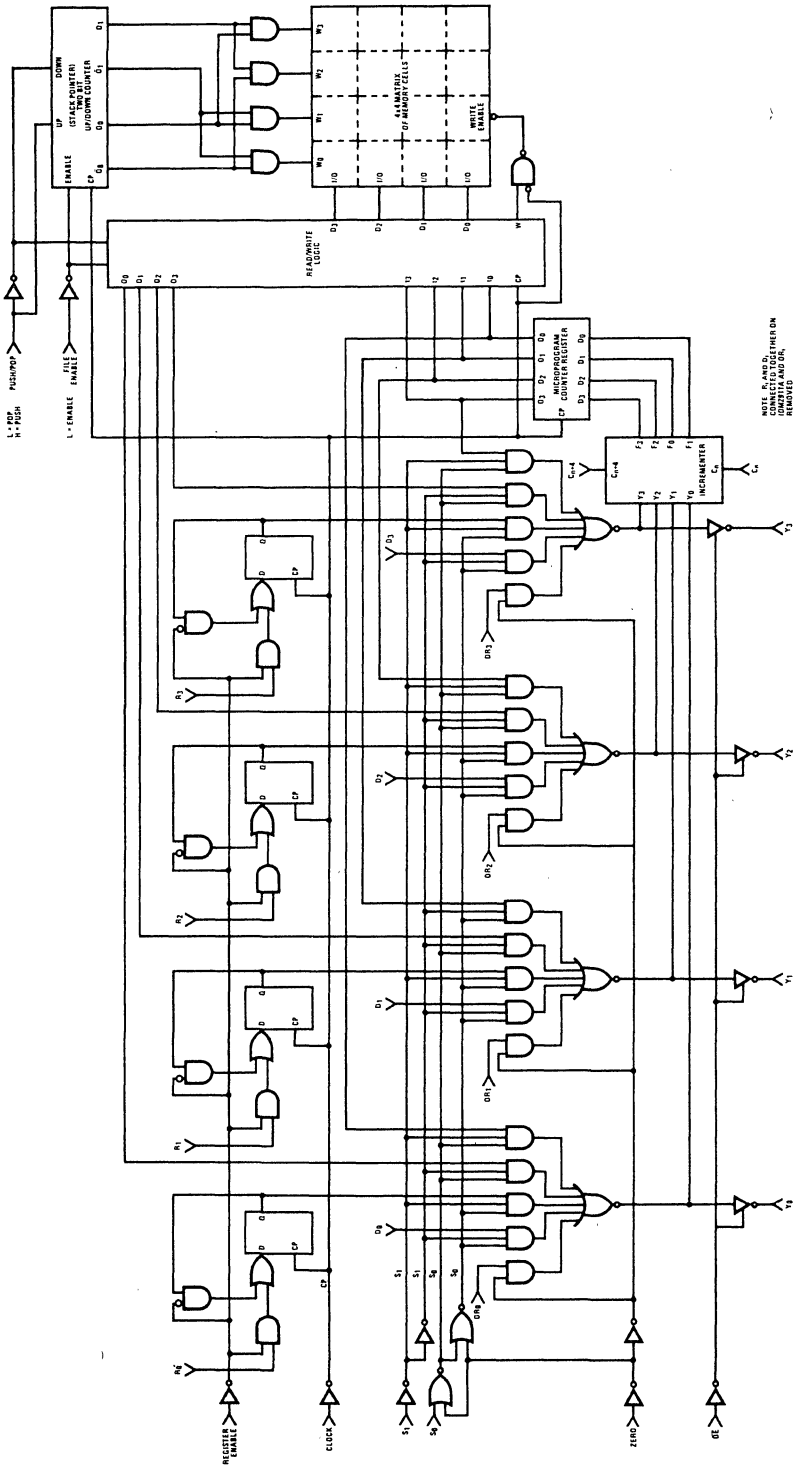


Figure 2. Microprogram Sequencer - Detailed Block Diagram

The microprogram counter consists of a 4-bit incrementer followed by a 4-bit register. The carry-in (C_n) and carry-out (C_{n+4}) features of the incrementer make cascading to larger word lengths easy and straightforward. The microprogram counter can be used in either of two ways. When the least significant bit of C_n is high, the microprogram register (μPC) is loaded on the next clock cycle with the current output word (Y_0 - Y_3) plus 1, that is, $Y+1 \rightarrow \mu PC$; thus, sequential microinstructions are executed. When C_n is low, the "Y" outputs are not incremented; accordingly, the same microinstruction can be repeatedly executed. The last address source available at the input of the multiplexer is the 4-bit/4-word stack file; when executing subroutines, the file provides return address linkage. The 4-by-4 memory matrix contains a stack pointer (SP) that always points to the last word written in the file; thus, stack reference operations (looping) can be performed without a push or pop. The stack pointer operates as an up/down counter with separate PUSH/POP and FILE ENABLE inputs. When the enable signal is low and the other signal is high, the "push" operation is enabled. Under these conditions, the stack pointer is incremented and the file is written with the required return linkage, that is, the next microinstruction address following the subroutine jump that initiated the "push." If both input signals (PUSH/POP and FILE ENABLE) are low, a "pop" operation is implemented. During this clock cycle, the return linkage is used to return from the subroutine; the next low-to-high transition of the clock pulse decrements the stack pointer.

When the FILE ENABLE signal is high, the stack pointer is not incremented or decremented, regardless of whether the PUSH/POP signal is high or low. Linkage of the stack pointer is such that any combination of pushes, pops, or stack references can be implemented; one microinstruction subroutine can be performed. Since the stack is 4 words deep, up to four microsubroutines can be nested. The ZERO input is used to force all four outputs (Y_0 - Y_3) of the multiplexer to the zero (logic 0) state. When the zero input is low, all Y-outputs are low, unless overridden by the OUTPUT ENABLE (\overline{OE}) signal. Also, each bit of the Y-output word can be ORed at the input such that conditional logic can be enforced; this allows execution of microinstructions to occur in any programmed sequence.

Definition of Terms and Symbols (Figure 2)

Inputs to IDM2909A/11A:

S_0/S_1	Control lines for address-source selection
\overline{FE}/PUP	Control lines for push/pop stack
\overline{RE}	Enable signal for internal address register
OR_i	Logic OR input for each address output line
\overline{ZERO}	Logic AND input for all output lines
\overline{OE}	Output Enable; when \overline{OE} is high, the Y-outputs are TRI-STATE (high impedance)
C_n	Carry-in to incrementer
R_i	Inputs to the internal address register
D_i	Direct inputs to the multiplexer
CP	Clock inputs

Outputs from the IDM2909A/11A:

Y_i	Address outputs; address inputs to control memory
C_{n+4}	Carry-out from the incrementer
μPC	Contents of the microprogram counter
REG	Contents of the internal register
STK0/STK3	Contents of the push/pop stack. By definition, the word addressed by the stack pointer in the 4-by-4 file is STK0. Data is pushed onto the stack at STK0 and is subsequently pushed to STK1, STK2, and finally to STK3. When the stack is popped, data is removed in the following order: STK3 \rightarrow STK2 \rightarrow STK1, and then to STK0. When a push or pop occurs, only the stack pointer changes — the data is not physically shifted within the stack.
SP	Contents of the stack pointer

Terms and symbols external to the IDM2909A/11A:

A	Control memory address
I(A)	Instruction in control memory at address "A"
μWR	Contents of microword register at output of control memory; this register contains the instruction currently being executed
T_n	Period of timing cycle

Operation of the IDM2909A/11A

Select codes for the multiplexer and the truth tables for output control/stack control are shown in figure 3. The two bits (S_0/S_1) from the microword register (plus additional branching logic) determine the data source for the next microinstruction address. The selected data source appears on the Y-outputs of the multiplexer.

A state table for S_0 , S_1 , \overline{FE} , and PUP is shown in figure 4; these signals define not only the address specified by the Y-outputs, but also the state of all internal registers, following the low-to-high transition of the clock pulse. In figure 4, it is assumed that the microprogram counter initially contains some word "J," word "K" is in the address register, and words R_a through R_d are contained in the 4-word push/pop stack.

The sequence for executing a subroutine using the IDM2909A is illustrated in figure 5. For any given clock cycle, the instruction being executed is contained in the microword register (μWR); the contents of this register also directly (or indirectly) control S_0 , S_1 , \overline{FE} , and PUP. At the appropriate time, the starting address of the subroutine is applied to the "D" inputs of the sequencer. The three left-hand columns of figure 5 show the execution sequence of the instructions and the designated execution cycles. At address "J+2," the sequence-control part of the microinstruction contains the command "Jump To Subroutine A." At time t_2 , the "J+2" instruction resides in the μWR and the inputs of the sequencer are set up to execute the "jump," and to save the return address. Address bits for subroutine "A" are taken from the microword register and applied to the D-inputs of the multiplexer; the output appears at the Y-port of the multiplexer.

Address Selection

Octal	S ₁	S ₀	Source for Y Outputs	Symbol
0	L	L	Microprogram Counter	μPC
1	L	H	Register	REG
2	H	L	Push-Pop Stack	STK0
3	H	H	Direct Inputs	D _i

Output Control

OR _i	ZERŌ	ŌE	Y _i
X	X	H	Z
X	L	L	L
H	H	L	H
L	H	L	Source selected by S ₀ S ₁

Z = High Impedance

Synchronous Stack Control

FE	PUP	Push-Pop Stack Change
H	X	No change
L	H	Increment stack pointer, then push current PC onto STK0
L	L	Pop stack (decrement stack pointer)

H = High

L = Low

X = Don't Care

Figure 3. Truth Tables for Multiplexer Control Signals

Cycle	S ₁ , S ₀ , FE, PUP	μPC	REG	STK0	STK1	STK2	STK3	YOUT	Comment	Principal Use
N N+1	0 0 0 0 —	J J+1	K K	R _a R _b	R _b R _c	R _c R _d	R _d R _a	J —	Pop Stack	End Loop
N N+1	0 0 0 1 —	J J+1	K K	R _a J	R _b R _a	R _c R _b	R _d R _c	J —	Push μPC	Set Up Loop
N N+1	0 0 1 X —	J J+1	K K	R _a R _a	R _b R _b	R _c R _c	R _d R _d	J —	Continue	Continue
N N+1	0 1 0 0 —	J K+1	K K	R _a R _b	R _b R _c	R _c R _d	R _d R _a	K —	Pop Stack; Use AR for Address	End Loop
N N+1	0 1 0 1 —	J K+1	K K	R _a J	R _b R _a	R _c R _b	R _d R _c	K —	Push μPC; Jump to Address in AR	JSR AR
N N+1	0 1 1 X —	J K+1	K K	R _a R _a	R _b R _b	R _c R _c	R _d R _d	K —	Jump to Address in AR	JMP AR
N N+1	1 0 0 0 —	J R _a +1	K K	R _a R _b	R _b R _c	R _c R _d	R _d R _a	R _a —	Jump to Address in STK0; Pop Stack	RTS
N N+1	1 0 0 1 —	J R _a +1	K K	R _a J	R _b R _a	R _c R _b	R _d R _c	R _a —	Jump to Address in STK0; Push μPC	
N N+1	1 0 1 X —	J R _a +1	K K	R _a R _a	R _b R _b	R _c R _c	R _d R _d	R _a —	Jump to Address in STK0	Stack Ref (Loop)
N N+1	1 1 0 0 —	J D+1	K K	R _a R _b	R _b R _c	R _c R _d	R _d R _a	D —	Pop Stack; Jump to Address on D	End Loop
N N+1	1 1 0 1 —	J D+1	K K	R _a J	R _b R _a	R _c R _b	R _d R _c	D —	Jump to Address on D; Push μPC	JSR D
N N+1	1 1 1 X —	J D+1	K K	R _a R _a	R _b R _b	R _c R _c	R _d R _d	D —	Jump to Address on D	JMP D

X = Don't Care, 0 = Low, 1 = High, Assume C_N = High
 Note: STK0 is the location addressed by the stack pointer.

Figure 4. Output and Internal Next-Cycle Register States for IDM2909A/11A

Applications Example

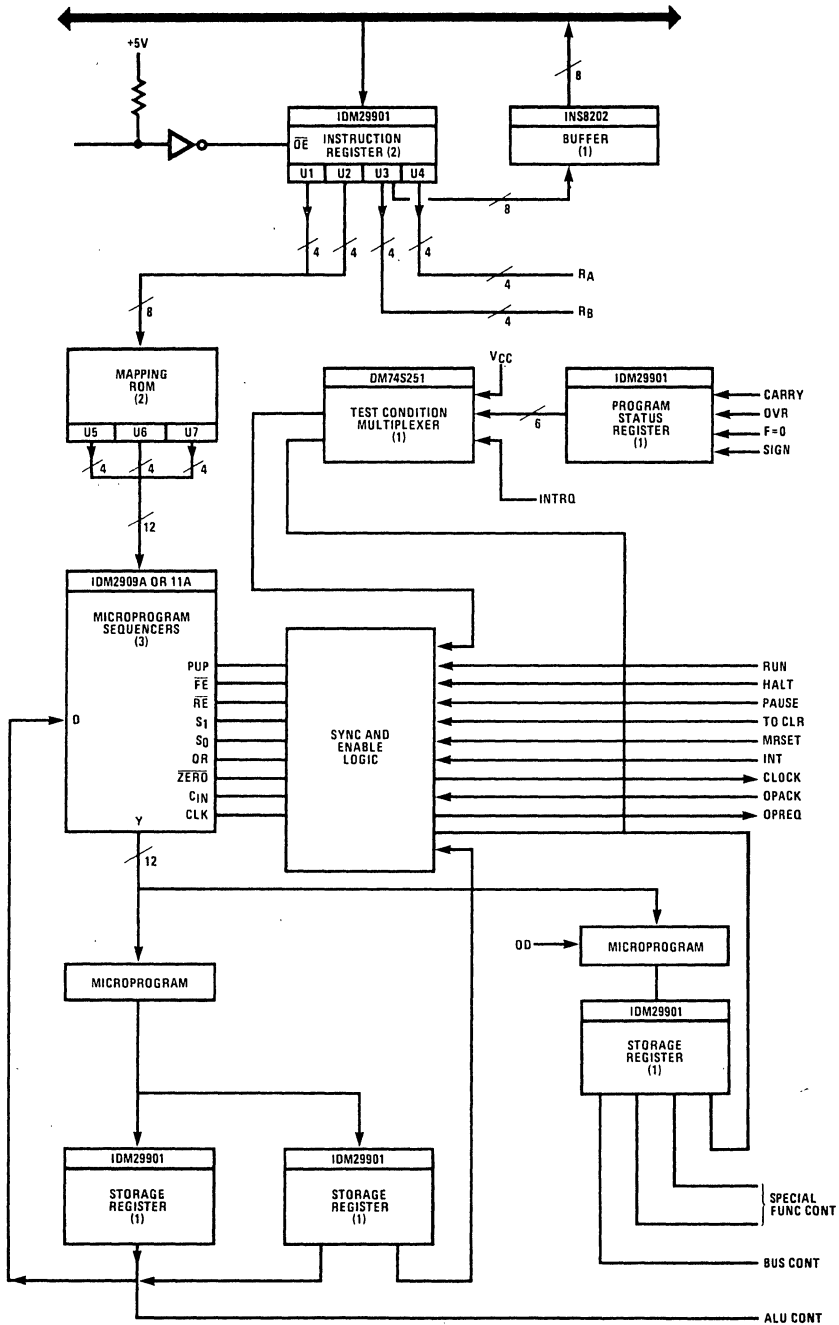


Figure 7. Typical Use of an IDM2909A as a Microprogram Sequencer in a Computer Control Unit

IDM2910A Microprogram Controller

General Description

The IDM2910A Microprogram Controller is a 12-bit wide address controller packaged in a standard 40-pin dual-in-line package. The IDM2910A features TRI-STATE® outputs and is fabricated using SCL (Schottky ECL) technology. The IDM2910A is a microprogram memory address controller that controls the execution sequence of microinstructions. In addition to being able to sequentially access memory, the IDM2910A is also able to conditionally branch to any microinstruction within the 4096 microinstruction range. A five-level last-in, first-out (LIFO) stack provides microsubroutine return linkage. An internal loop counter is included to provide the repeating instructions or perform up to 4096 loop iterations.

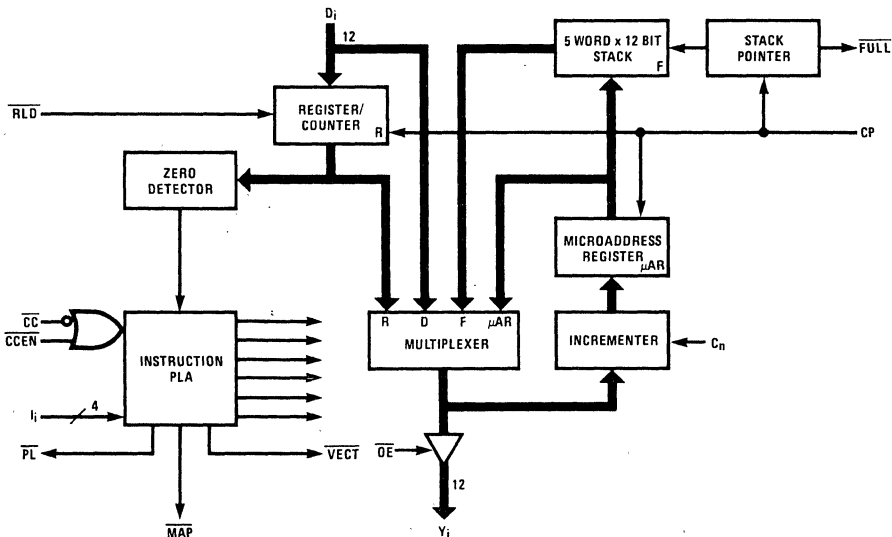
As each microinstruction is executed, the IDM2910A selects a 12-bit address from one of four sources:

1. The Microprogram Address Register which usually contains the increment address of the previous microinstruction.
2. The external Direct Input lines.
3. The Register/Counter which contains an address or data loaded during a previous microinstruction.
4. The LIFO Stack.

Features and Benefits

- Twelve-bit wide address — controls up to 4096 words of microcode with one device
- Internal register/counter — a 12-bit down-counter that may be used to count loop iterations
- Four address sources — the next microprogram address selected from the microprogram address/register data input lines, LIFO stack, or register counter
- Sixteen powerful microinstructions — executes 16 sequence control instructions
- Output enables for three branch address sources — replaces either external decoder or additional bit of microcode
- Positive-edge triggering for all internal registers
- Fast condition-code control — typically a 19ns delay from a condition-code input to an address output
- SCL technology — provides ECL speeds while maintaining low-power Schottky power consumption
- 100% reliability testing in compliance with MIL-STD-883.

IDM2910A Block Diagram



Absolute Maximum Ratings

Storage Temperature	-65 °C to +150 °C
Temperature (Ambient) Under Bias	-55 °C to +125 °C
Supply Voltage to Ground Potential	-0.5V to +6.3V
DC Voltage Applied to Outputs for High Output State	-0.5V to +V _{CC} max
DC Input Voltage	-0.5V to +5.5V
DC Output Current, into Outputs	30 mA
DC Input Current	-30 mA to +5.0 mA

Operating Range

Part Number	Ambient Temperature	V _{CC}
IDM2910A JC, NC	0 °C to +70 °C	4.75V to 5.25V
IDM2910A JM, JM/883	-55 °C to +125 °C	4.50V to 5.50V

Standard Screening (Conforms to MIL-STD-883 for Class C parts)

Step	MILSTD-883 Method	Conditions	Level	
			DC, NC	DM
Pre-Seal Visual Inspection	2010	B	100%	100%
Stabilization Bake	1008	C: 24-hour 150 °C	100%	100%
Temperature Cycle	1010	C: -65 °C to +150 °C 10 cycles	100%	100%
Centrifuge	2001	B: 10,000 G	100% *	100%
Fine Leak	1014	A: 5×10^{-8} atm-cc/cm ³	100% *	100%
Gross Leak	1014	C2: Fluorocarbon	100% *	100%
Electrical Test Subgroups 1, 7, and 9	5004	See below for definitions of subgroups	100%	100%
Insert Additional Screening here for Class B parts				
Group A Sample Tests Subgroup 1 Subgroup 2 Subgroup 3 Subgroup 7 Subgroup 8 Subgroup 9	5005	See below for definitions of subgroups	LTPD = 5 LTPD = 7 LTPD = 7 LTPD = 7 LTPD = 7 LTPD = 7	LTPD = 5 LTPD = 7 LTPD = 7 LTPD = 5 LTPD = 7 LTPD = 5

*Not applicable to IDM2910ANC.

Additional Screening for Class B Parts

Step	MIL-STD-883 Method	Conditions	Level DM/883
Burn-In	1015	D: 125 °C, 160 hours min	100%
Electrical Test Subgroup 1	5004		100%
Subgroup 2			100%
Subgroup 3			100%
Subgroup 7			100%
Subgroup 9			100%
Return to Group A Tests in Standard Screening			

Group A Subgroups

(as defined in MILSTD-883, method 5005)

Subgroup	Parameter	Temperature
1	DC	25 °C
2	DC	Maximum rated temperature
3	DC	Minimum rated temperature
7	Function	25 °C
8	Function	Maximum and minimum rated temperature
9	Switching	25 °C
10	Switching	Maximum rated temperature
11	Switching	Minimum rated temperature

Electrical Characteristics

The following conditions apply unless otherwise specified:

Comm'l $T_A = 0^\circ\text{C to } +70^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 5\%$ min = 4.75V max = 5.25V

Mil $T_C = -55^\circ\text{C to } +125^\circ\text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$ min = 4.50V max = 5.50V

DC Characteristics over Operating Range

Symbol	Description	Test Conditions (Note 1)	Min	Typ (Note 2)	Max	Units	
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{min}$, $I_{OH} = -5\text{mA}$, $V_{IN} = V_{IH}$ or V_{IL}	2.4			V	
V_{OL}	Output LOW Voltage	$V_{CC} = \text{min}$, $V_{IN} = V_{IH}$ or V_{IL} , $Y_{0-11} I_{OL} = 12\text{mA}$ (Comm'l) $Y_{0-11} I_{OL} = 12\text{mA}$ (Mil) PL, VECT, MAP, FULL $I_{OL} = 8\text{mA}$			0.5	V	
V_{IH}	Input HIGH Level (Note 4)	guaranteed input logical HIGH voltage for all inputs	2.0			V	
V_{IL}	Input LOW Level (Note 4)	guaranteed input logical LOW voltage for all inputs			0.8	V	
V_I	Input Clamp Voltage	$V_{CC} = \text{min}$, $I_{IN} = -18\text{mA}$			-1.5	V	
I_{IL}	Input LOW Current	$V_{CC} = \text{max}$, $V_{IN} = 0.5\text{V}$			-0.36	mA	
I_{IH}	Input HIGH Current	$V_{CC} = \text{max}$, $V_{IN} = 2.7\text{V}$			30	μA	
I_I	Input HIGH Current	$V_{CC} = \text{max}$, $V_{IN} = 5.5\text{V}$			1.0	mA	
I_{SC}	Output Short Circuit Current (Note 3)	$V_{CC} = \text{max}$	-20		-85	mA	
I_{OZL}	Output OFF Current	$V_{CC} = \text{max}$, $\overline{OE} = 2.4\text{V}$, $V_{OUT} = 0.5\text{V}$			-50	μA	
I_{OZH}	Output OFF Current	$V_{CC} = \text{max}$, $OE = 2.4\text{V}$, $V_{OUT} = 2.4\text{V}$			50	μA	
I_{CC}	Power Supply Current	$V_{CC} = \text{max}$ $T_A = 25^\circ\text{C}$		160	245	mA	
	IDM2910A DC, NC	$T_A = 0^\circ\text{C to } +70^\circ\text{C}$			260	mA	
		$T_A = +70^\circ\text{C}$				220	mA
	IDM2910A DM, DM/883	$T_C = -55^\circ\text{C to } +125^\circ\text{C}$				275	mA
		$T_C = +125^\circ\text{C}$				185	mA

Notes:

- For conditions shown as min or max, use the appropriate value specified under Electrical Characteristics for the applicable device type.
- Typical limits are at $V_{CC} = 5.0\text{V}$, 25°C ambient and maximum loading.
- Not more than one output should be shorted at a time. Duration of the short circuit test should not exceed one second.
- These input levels provide no guaranteed noise immunity and should be tested only in a static and noise-free environment.

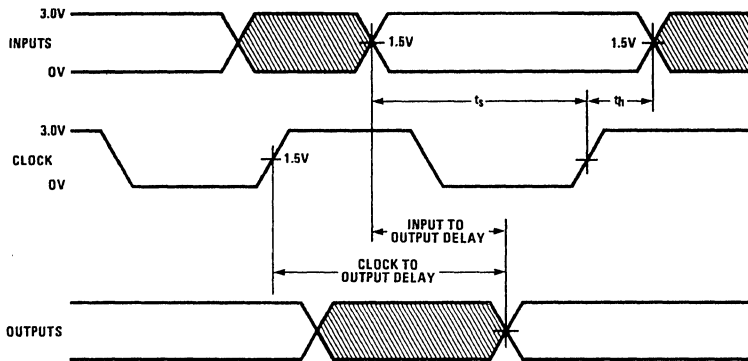


Figure 1. Switching Waveforms

Setup (t_s) and hold (t_h) times for varied inputs are listed in Table A. Combinational input to output delays are listed in Table B. Clock requirements are listed in Table C. See Figure 3, Switching Waveform Timing, for a typical cycle.

Switching Characteristics

(Refer to Figure 1.)

IDM2910A switching characteristics for the typical, commercial and military operating ranges available are given in Tables A, B, and C on this page and the following page.

Table A contains setup and hold times with respect to the clock low-to-high transition. Table B contains combinational delays from input to output. Table C contains the clock requirements.

All measurements are made at 1.5V with input levels at 0V or 3V. All times are in nanoseconds.

Typical Room Temperature Characteristics

($T_A = 25^\circ\text{C}$, $V_{CC} = 5.0\text{V}$, $C_L = 50\text{pF}$)

A. Setup and Hold Times

Input	t_s	t_h
$D_i \rightarrow R$	11	6
$D_i \rightarrow AR$	15	6
$I_0 - I_3$	35	6
\overline{CC}	22	6
\overline{CCEN}	21	6
C_n	19	6
\overline{RLD}	21	6

B. Combinational Delays

Input	Y	PL, VECT, MAP	FULL
$D_0 - D_{11}$	14	—	—
$I_0 - I_3$	24	20	—
\overline{CC}	21	—	—
\overline{CCEN}	21	—	—
CP $I = 8, 9, 15$	28	—	—
CP (Note) $I = 8, 9, 15$	28	—	—
CP All Other I	24	—	28
\overline{OE}	15/15	—	—

Note: If the instruction prior to the clock was 4 or 12 or \overline{RLD} was low, delays are as listed.

C. Clock Requirements

Minimum Clock LOW Time	25	ns
Minimum Clock HIGH Time	25	ns
Minimum Clock Period, $I = 8, 9, 15$	50	ns
Minimum Clock Period, $I = 14$	50	ns

Clock periods for other instructions are determined by external conditions.

Guaranteed Characteristics over Commercial Operating Range

IDM2910A DC, NC

(T_A = 0°C to +70°C, V_{CC} = 4.75V to 5.25V, C_L = 50 pF)

A. Setup and Hold Times

Input	t _s	t _h
D _i → R	14	0
D _i → AR	25	0
I ₀ -I ₃	35	0
CC	35	0
CCEN	35	0
C _n	30	0
R _{LD}	25	0

B. Combinational Delays

Input	Y	PL, VECT, MAP	FULL
D ₀ -D ₁₁	20	—	—
I ₀ -I ₃	35	30	—
CC	35	—	—
CCEN	35	—	—
CP I = 8, 9, 15	45	—	—
CP (Note) I = 8, 9, 15	45	—	—
CP All Other I	35	—	30
OE	25/25	—	—

Note: If the instruction prior to the clock was 4 or 12 or R_{LD} was low, delays are as listed.

C. Clock Requirements

Minimum Clock LOW Time	30	ns
Minimum Clock HIGH Time	30	ns
Minimum Clock Period, I = 8, 9, 15	60	ns
Minimum Clock Period, I = 14	60	ns

Clock periods for other instructions are determined by external conditions.

Guaranteed Characteristics over Military Operating Range

IDM2910A DM, DM/883

(T_A = -55°C to +125°C, V_{CC} = 4.5V to 5.5V, C_L = 50 pF)

A. Setup and Hold Times

Input	t _s	t _h
D _i → R	17	0
D _i → AR	30	0
I ₀ -I ₃	40	0
CC	40	0
CCEN	40	0
C _n	35	0
R _{LD}	30	0

B. Combinational Delays

Input	Y	PL, VECT, MAP	FULL
D ₀ -D ₁₁	25	—	—
I ₀ -I ₃	40	35	—
CC	40	—	—
CCEN	40	—	—
CP I = 8, 9, 15	55	—	—
CP (Note) I = 8, 9, 15	55	—	—
CP All Other I	40	—	35
OE	25/25	—	—

Note: If the instruction prior to the clock was 4 or 12 or R_{LD} was low, delays are as listed.

C. Clock Requirements

Minimum Clock LOW Time	35	ns
Minimum Clock HIGH Time	35	ns
Minimum Clock Period, I = 8, 9, 15	70	ns
Minimum Clock Period, I = 14	70	ns

Clock periods for other instructions are determined by external conditions.

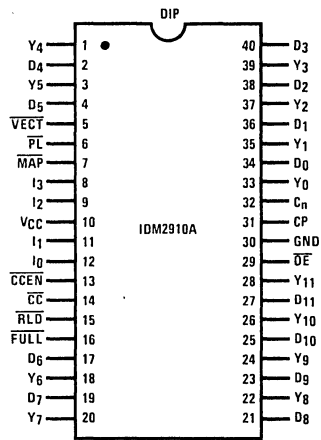


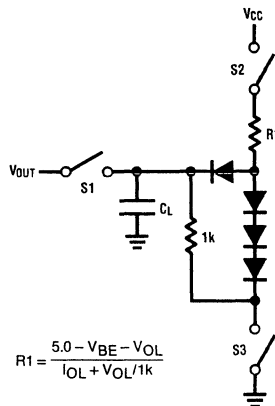
Figure 2. Pin Connection Diagram

Table 1. IDM2910A Pinout Descriptions

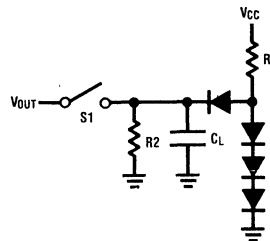
Abbreviation	Name	Function
$D_i, i = 0 \text{ to } 11$	Direct Inputs	12 direct input lines carrying data into the register/counter or a jump address to be used by the multiplexer. D_0 is LSB.
$I_i, i = 0 \text{ to } 3$	Instruction Lines	Four instruction lines. Select one-of-sixteen control instructions for the IDM2910A.
\overline{CC}	Condition Code	The outcome of a test is input through this line into the IDM2910A so that it may be used in conditional control instructions. A low on \overline{CC} is interpreted as PASS test.
\overline{CCEN}	Condition Code Enable	Conditional control based on the \overline{CC} input is enabled as long as \overline{CCEN} is low. A high on \overline{CCEN} overrides the \overline{CC} input and the IDM2910A will operate as if \overline{CC} were low.
C_n	Carry In	The carry input to the address register incrementer.
\overline{RLD}	Register Load	When LOW, will force a load of the register/counter on the next rising edge of the clock. Loading will be performed regardless of instruction or condition.
\overline{OE}	Output Enable	The TRI-STATE [®] control of Y_i outputs.
CP	Clock Pulse	All internal state changes are triggered by the rising edge of the clock.
V_{CC}	+5 Volts	
GND	Ground	
$Y_i, i = 0 \text{ to } 11$	Address Outputs	12 address output lines to be used by the microprogram memory in accessing the next microword. Y_0 is LSB.
\overline{FULL}	Full Stack	This output will go low one microcycle after the stack becomes full.
\overline{PL}	Pipeline Address Enable	May be used to enable the first of three sources (usually pipeline register) onto the branch address bus connected to the D_i inputs.
\overline{MAP}	Map Address Enable	May be used to enable the second of three sources (mapping ROM, PROM or RAM) onto the branch address bus connected to the D_i inputs.
\overline{VECT}	Vector Address Enable	May be used to enable the third of three sources (usually interrupt starting address) onto the branch address bus connected to the D_i inputs.

Test Output Load Configurations for IDM2910A

A. Three-State Outputs



B. Normal Outputs



$$R2 = \frac{2.4V}{I_{OH}}$$

$$R1 = \frac{5.0 - V_{BE} - V_{OL}}{I_{OL} + V_{OL}/R2}$$

Note 1: $C_L = 50$ pF includes scope probe, wiring and stray capacitances without device in test fixture.

Note 2: S1, S2, S3 are closed during function tests and all AC tests except output enable tests.

Note 3: S1 and S3 are closed while S2 is open for t_{pZH} test.

S1 and S2 are closed while S3 is open for t_{pZL} test.

Note 4: $C_L = 5.0$ pF for output disable tests.

Test Output Loads for IDM2901A

Pin # (DIP)	Pin Label	Test Circuit	R1	R2
—	Y_{0-11}	A	300	1k
5	\overline{VECT}	B	470	1.5k
6	\overline{PL}	B	470	1.5k
7	\overline{MAP}	B	470	1.5k
16	\overline{FULL}	B	470	1.5k

The IDM2910A Microinstruction Set

The IDM2910A executes sixteen control instructions. These instructions perform specific functions in addition to the selection of the next microcode word to be executed.

Four of the control instructions are unconditional — the function performed is specified only by the instruction itself.

Ten of the control instructions are conditional branches — based upon the state of an external data-dependent test. Since test results may be forced by suitable circuitry, it follows that the ten control instructions may also be used as unconditionals.

Three of the instructions allow conditional sequencing based upon the contents of the internal register/counter.

The IDM2910A instruction control set is shown in Table 2. One of the conditional branch control instructions is dependent on the external data test and the contents of the internal register/counter.

For the following discussion it is assumed that C_n is tied high.

For the ten conditional control instructions, the results of data dependent tests are applied to the condition code input, \overline{CC} . If the input to \overline{CC} is low, the test is considered passed and the action specified under "PASS" (Table 2) will be taken. If the input to \overline{CC} is high, the test is considered failed and the alternate action is taken. In many cases, the alternate action is the selection of the sequentially incremented address. By setting \overline{CCEN} high for any specific microinstruction, \overline{CC} testing will be disabled and a "PASS" will be forced. Other suggestions for using \overline{CCEN} to save one bit of microcode are:

- If there is no data-dependent microcode, \overline{CCEN} can be tied high.
- If data-dependent control instructions are never forced unconditionally, \overline{CCEN} can be tied low.
- If \overline{CCEN} is tied to the source of the IDM2910A instruction bit I_0 , control instructions 4, 6, and 10 are left as data-dependent, and the others are made unconditional.

Several of the IDM2910A inputs may be used to modify instruction execution. For 10 of the 16 instructions, the combination of \overline{CC} high and \overline{CCEN} low is used as a test. When \overline{RLD} is low, the direct inputs are loaded into the register/counter overriding any HOLD or DECREMENT (DEC) operation specified in the microinstruction. The \overline{OE} input, normally low, may be driven high to place the Y outputs in the TRI-STATE[®] condition.

The LIFO stack contains a 5-word, 12-bit file memory and a stack pointer which addresses the value presently at the top of the stack. Actual control over the stack pointer is possible when using microinstruction 0 (JUMP ZERO or RESET). This microinstruction clears the stack by resetting the stack pointer to zero. The contents at the top of the stack will remain undefined following execution of microinstruction 0, or whenever the stack becomes empty. Any pops performed while the stack is empty will place an undefined address at the F inputs to the multiplexer and the stack pointer will remain at zero.

If five more pushes than pops have occurred since the stack was last empty, the stack will become full. Once the stack is full, the FULL output will go low. FULL will go low on the first microcycle following the fifth push. If any additional push operations are performed on a full stack, the stack becomes overwritten and any previous information is lost.

Table 2. IDM2910A Microinstruction Set

Hex I_3-I_0	Mnemonic	Name	Reg/Cntr Contents	FAIL $\overline{CCEN} = \text{LOW}$ and $\overline{CC} = \text{HIGH}$		PASS $\overline{CCEN} = \text{HIGH}$ or $\overline{CC} = \text{LOW}$		Reg/ Cntr	Enable
				Y	Stack	Y	Stack		
				0	JZ	JUMP ZERO	X		
1	CJS	COND JSB PL	X	PC	HOLD	D	PUSH	HOLD	PL
2	JMAP	JUMP MAP	X	D	HOLD	D	HOLD	HOLD	MAP
3	CJP	COND JUMP PL	X	PC	HOLD	D	HOLD	HOLD	PL
4	PUSH	PUSH COND LD CNTR	X	PC	PUSH	PC	PUSH	Note 1	PL
5	JSRP	COND JSB R/PL	X	R	PUSH	D	PUSH	HOLD	PL
6	CJV	COND JUMP VECTOR	X	PC	HOLD	D	HOLD	HOLD	VECT
7	JRP	COND JUMP R/PL	X	R	HOLD	D	HOLD	HOLD	PL
8	RFCT	REPEAT LOOP, CNTR $\neq 0$	$\neq 0$	F	HOLD	F	HOLD	DEC	PL
			$= 0$	PC	POP	PC	POP	HOLD	PL
9	RPCT	REPEAT PL, CNTR $\neq 0$	$\neq 0$	D	HOLD	D	HOLD	DEC	PL
			$= 0$	PC	HOLD	PC	HOLD	HOLD	PL
A	CRTN	COND RTN	X	PC	HOLD	F	POP	HOLD	PL
B	CJPP	COND JUMP PL & POP	X	PC	HOLD	D	POP	HOLD	PL
C	LDCT	LD CNTR & CONTINUE	X	PC	HOLD	PC	HOLD	LOAD	PL
D	LOOP	TEST END LOOP	X	F	HOLD	PC	POP	HOLD	PL
E	CONT	CONTINUE	X	PC	HOLD	PC	HOLD	HOLD	PL
F	TWB	THREE-WAY BRANCH	$\neq 0$	F	HOLD	PC	POP	DEC	PL
			$= 0$	D	POP	PC	POP	HOLD	PL

Note 1: If $\overline{CCEN} = \text{LOW}$ and $\overline{CC} = \text{HIGH}$, hold; else load. X = Don't Care.

IDM2910A Architecture

The IDM2910A Bipolar Microprogram Controller is intended for use in very high-speed microprocessor applications. Up to 4096 microwords may be addressed using the IDM2910A.

A multiplexer within the IDM2910A selects one of four inputs as the source of the next microinstruction address. The four sources are:

1. the microprogram address register (μ AR)
 2. the register/counter
 3. the direct input lines
 4. the LIFO stack
1. The Microprogram Address Register contains a twelve-bit incrementer followed by a twelve-bit register. Two uses for the microprogram address register are:
 - a. When carry-in (C_n) is high, the current microprogram address plus one ($Y_i + 1$) is loaded into the address register on the next positive clock transition. Therefore, microprogram words are accessed sequentially.
 - b. When carry-in (C_n) is low, the current microprogram address is passed through the incrementer and loaded into the address register on the next position clock transition. Thus, the same microinstruction may be repeated as often as is required.
 2. The register/counter contains twelve D-type edge-triggered flip-flops with a common clock enable. When the register load control (\overline{RLD}) is low, addresses from the direct input bus are loaded into the register on the next positive-going clock. Some sequence control instructions include a load operation. For most microcomputer systems, these instructions will be sufficient, thereby simplifying the microcode.
 3. The Direct Input lines are a direct input source which may be used for microprogram branching.
 4. The LIFO stack is a 5-word by 12-bit stack used to provide return address linkage when executing microsubroutines or loops. The stack incorporates a

5×12 file (RAM) and a stack pointer that always points to the last entry into the file. Stack reference operations (microprogram looping) may be executed without popping the stack.

The stack pointer is an up/down counter that is incremented whenever a push operation is performed (microinstructions 1, 4, and 5). Once the pointer is incremented, the return address is written into the location indicated by the stack pointer on the positive-going clock following the push.

The stack pointer is decremented whenever the pop operation is performed (microinstructions 8, 10, 11, 13, and 15). The stack pointer is decremented on the positive-going clock following a pop, effectively removing the return address from the top of the stack.

Stack pointer linkage is such that any combination of pushes, pops, or stack references may be performed. For control instruction 0 (JUMP ZERO or RESET), the stack pointer is reset. For each push operation, the microsubroutine nesting depth is increased by one; for each pop operation, the depth decreases by one. The maximum nesting depth is five. Once the stack becomes full, \overline{FULL} goes low and the stack pointer can no longer be incremented. Further pushes will write over the preceding address at the top of the stack. A pop from an empty stack (stack pointer at zero) will place a meaningless address on the Y outputs, and the stack pointer will remain at zero. A stack pointer at zero remains unchanged by any number of additional pops.

The register/counter operates as a twelve-bit down-counter during microinstructions 8, 9, and 15, with register contents zero as a branch condition. This branch condition provides efficient repetition of microinstructions. The internal arrangement of the register/counter is such that if a number N is loaded into it and the register is used as a loop termination counter, the sequence will be executed N + 1 times. A three-way branch condition is available (control instruction 15) under control of both the register/counter and the condition code input (\overline{CC}).

The Y output lines are TRI-STATE[®] allowing the Y outputs to be disabled. When disabled (via \overline{OE}), the address lines can be externally driven, allowing automatic checkout of the microcomputer system.

Architectures Using the IDM2910A

Shading illustrates paths which can limit speed.

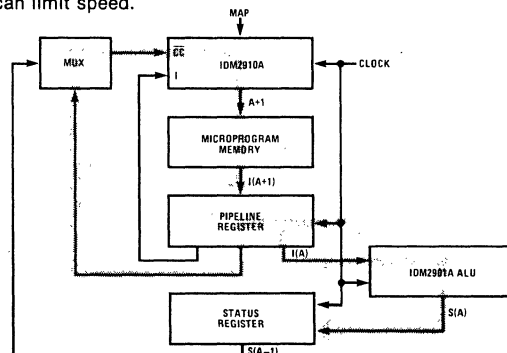


Figure 3a. Single-Level Pipeline Based Architecture

A one-level pipeline provides for better speed than most other architectures. The IDM2910A array and the microprogram memory are in parallel speed paths, rather than in series. This architecture is recommended for IDM2910A designs.

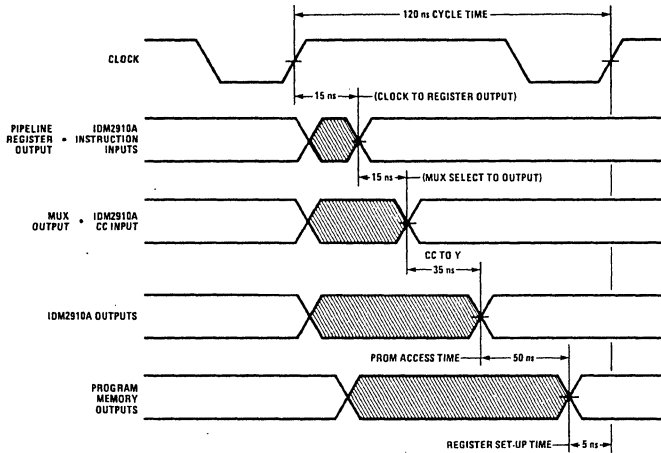


Figure 3b. Typical Timing Waveform for Single-Level Pipeline Based Architecture

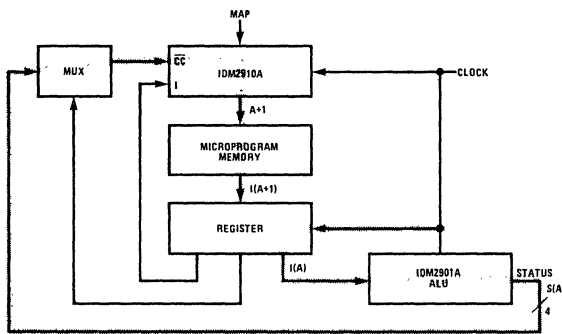


Figure 4. Instruction Based Architecture

The microinstruction being executed is in the register at the microprogram memory output. The IDM2910A and the microprogram memory are in series. Any conditional branches are executed on the same cycle as the ALU operation generating the condition.

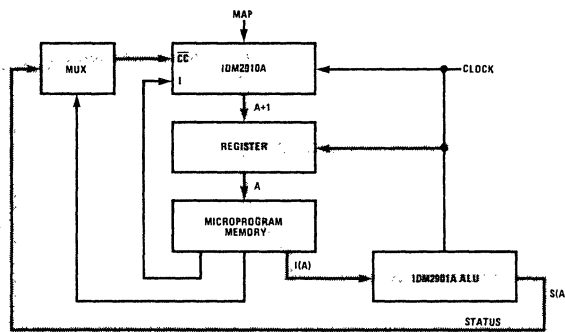


Figure 5. Address Based Architecture

The address of the microinstruction being executed is in the register at the IDM2910A output. The IDM2910A and the microprogram memory are in the critical path. This architecture operates at approximately the same speed as the instruction based architecture, but requires fewer register bits because only the address (typically 10 to 12 bits) is stored instead of the instruction (typically 40 to 60 bits).

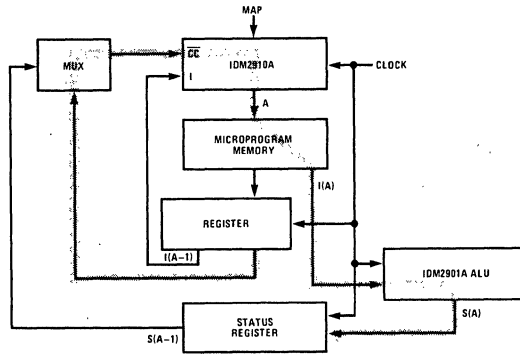


Figure 6. Data Based Architecture

The status register provides for conditional branch control based upon the results of the previous ALU cycle. The IDM2910A and the microprogram memory are in the critical path.

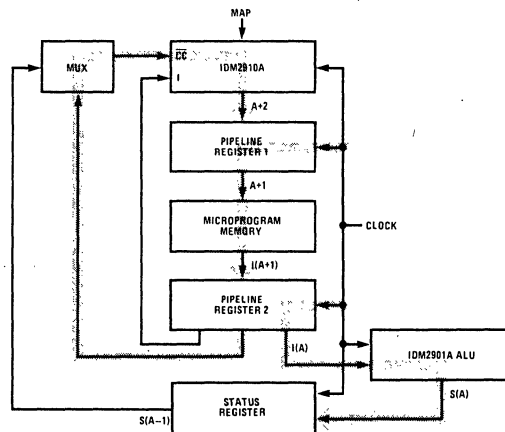


Figure 7. Two-Level Pipeline Architecture

The two-level pipeline provides the maximum possible speed, but is more difficult to program because the selection of a microinstruction occurs two microinstructions ahead of its execution.

IDM2910A Operation

The results of each instruction in determining the Y outputs, and the controlling of the three enable signals (\overline{PL} , \overline{MAP} , \overline{VECT}) are given in Table 2. Also shown is the effect of the microinstructions on the register/counter and the stack after the next positive-going clock. The multiplexer determines which of the internal sources drive the Y output lines. Depending upon the condition of C_n , the address loaded into the microprogram address register will be identical to the Y outputs, or will be one greater. For each microinstruction, only one of the three enable outputs (\overline{PL} , \overline{MAP} , or \overline{VECT}) is low. These three enable signals may be used to control the TRI-STATE[®] outputs of three external sources of microprogram address to allow them to drive the direct input bus (D_i) without additional logic. The external sources are:

1. A source of microprogram jumps (usually part of a pipeline register).
2. A PROM which maps machine language to a microinstruction starting location (entry point).

3. An optional third source of microinstructions (often a vector from a DMA or interrupt source).

The function performed by three of the control instructions depends upon the contents of the register/counter. The counter is decremented if it contains a non-zero value. If the value in the counter is zero, it is held and a different microprogram next-address is selected. These types of instructions are useful for executing a microinstruction loop a known number of times. The three-way branch control instruction (number 15) is affected by both the external condition code \overline{CC} and the contents of the register/counter.

The following paragraphs describe each of the IDM2910A control instructions. Included with each of the descriptions is an execution flowchart showing typical microprogram flow.

Each of the examples is intended to show a typical microprogram flow as various microprogram control instructions are executed. The typical circuit of Figure 3 is assumed.

The microprogram addresses in the illustrations were chosen arbitrarily and have no significance other than

to illustrate microprogram flow, the only exception being control instruction 0, JZ (JUMP ZERO or RESET), which always selects the next address to be zero.

Execution flowcharts should be interpreted as follows:

Each dot relates to one microcycle. While this microcycle is going on the IDM2910A control instruction will be supplied by the microprogram memory word presently in the pipeline register.

A dot surrounded by a circle refers to the control instruction under discussion. Dashed lines refer to conditional actions. Solid lines refer to unconditional actions or to the outcome of =Test Failed= in conditional control instructions.

Dashed arrows refer to conditional branches (address changes other than sequential flow), which will be selected if the test is passed ($\overline{CC} = \text{LOW}$). Solid arrows refer to unconditional branches or to the outcome of =Test Failed= in conditional control instructions.

Parentheses () should be read "contents of," e.g., (D_i) = contents of D_i .

Control Instruction 0

JZ (Jump Zero or Reset) — This control instruction clears the stack pointer and specifies unconditionally that the next address is zero. This control instruction is useful for power-up sequences if the initialization routines start at microprogram memory location zero.

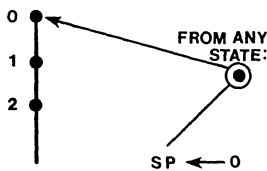


Figure 8. JUMP ZERO (JZ)

Control Instruction 1

CJS (Conditional Jump-to-Subroutine) — This control instruction executes a conditional jump to a subroutine located at the address found in the pipeline register. Referring to Figure 9, the unconditional microprogram flow is from address 50 through address 52. When the contents of address 52 are in the pipeline register, the next address control instruction is CJS. If the conditional test is passed, address 53 will be pushed onto the stack and the next instruction executed will be at address 90. The address pushed onto the stack provides a return link once the microsubroutine starting at address 90 is completed. For example, a Return-from-Subroutine (CRTN, control instruction 10) was executed at address 93. If the conditional test fails, the Jump-to-Subroutine will not be executed and the contents at address 53 will be executed. In this manner, the CJS control instruction at address 52 will cause the microprogram word at either address 90 or address 53 to be executed.

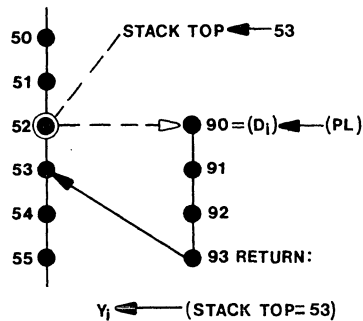


Figure 9. COND JSB PL (CJS)

Control Instruction 2

JMAP (Jump-Map) — This is an unconditional jump control instruction. When JMAP is executed, the \overline{MAP} output is enabled and the next microinstruction address is taken from the mapping PROMs. The JMAP control instruction is normally used towards the end of an instruction-fetch sequence for the microcomputer. At that time the next instruction to be executed should be valid, allowing it to be mapped into the corresponding entry point.

For the example shown, the microinstructions at addresses 50 through 53 would be the fetch sequence, with 53 being the sequence completion. The JMAP control instruction would be contained in the pipeline register with the mapping PROM generating an address 90. Address 90 would be selected by the IDM2910A as the next address to be presented to microprogram memory.

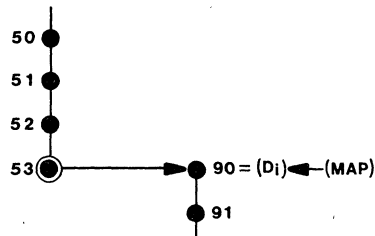


Figure 10. JUMP MAP (JMAP)

Control Instruction 3

CJP (Conditional Jump Pipeline) — This control instruction derives its branch address from the pipeline register branch address field (BR_0 through BR_{11}). See the typical microcomputer system, Figure 11. A technique is thus provided for branching to various microprogram sequences depending upon the state of the condition code inputs (\overline{CCEN} and \overline{CC}). State-machines may be designed to execute tests on various inputs and to wait for the condition to go true. When the condition does go true, the system branches and performs a specific function. When the branch occurs, the particular input is usually reset until some point in the future. With \overline{CCEN} high, this control instruction is the one to use for unconditional jumps.

The example illustrates a conditional jump via the address value defined by the microprogram word located at address 52. When the contents of address 52 are in the pipeline register, the next address passed through the IDM2910A will be either address 53 or address 30, depending upon the state of the condition code input. If the test passes, the address value in the pipeline register (address 30) will be selected by the IDM2910A. If the test fails, the next sequential address (address 53) contained in the micro address register (μ AR) will be selected.

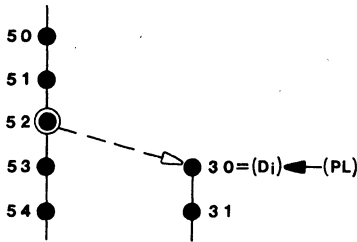


Figure 11. COND JUMP PL (CJP)

Control Instruction 4

PUSH (Unconditional Push/Conditional Load Counter)

— This control instruction is primarily used to set up microprogram loops in the microprogram. As shown in Figure 12, when microcode word 52 is in the pipeline register, a push operation is performed on the stack and depending upon the condition code inputs, the register/counter is loaded. A push operation causes the next sequential address (address 53) to be pushed onto the stack. If the condition code test fails, the register/counter is not loaded. If the condition code test passes, the register/counter is loaded with the address value in the pipeline register branch address field. In this manner, a single control instruction can set up a microprogram loop to be executed a specific number of times. While setup is being performed the IDM2910A will unconditionally select the next sequential address contained in the micro address register to be presented to the memory. Control instruction 8 (RFCT) describes the use of the pushed value and the register/counter contents for looping.

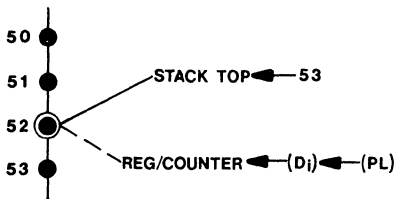


Figure 12. PUSH, COND LD CNTR (PUSH)

Control Instruction 5

JSRP (Conditional Jump-to-Subroutine) — This control instruction is a conditional jump to a subroutine via either the contents of the register/counter or the pipeline register.

As shown in Figure 13, a push operation is always performed and one of two microsubroutines is executed. For this example, either the microsubroutine at address 80 or the microsubroutine at location 90 will be executed. A Return-from-Subroutine (CRTN, control instruction 10) at the end of the microsubroutine will pop the return address (location 55) from the stack. In order for this microinstruction control sequence to operate correctly, the next address fields of both microinstructions 53 and 54 must contain the proper address value. As an example, the next address field of microinstruction 53 must contain address value 90 and microinstruction 54 must contain address value 80. Microinstruction 53 must be loaded into the register/counter while microinstruction 54 is in the pipeline register. If a JSRP is executed at address 54 and the condition code test fails, the contents of the register/counter will be passed through the IDM2910A as the address (address 90) of the next microinstruction. If the condition code test passes, the address value in the pipeline register will be passed through the IDM2910A as the address (address 80) of the next microinstruction. Therefore, this control instruction (JSRP) has the capability of selecting one of two microsubroutines, based upon the results of a condition code test.

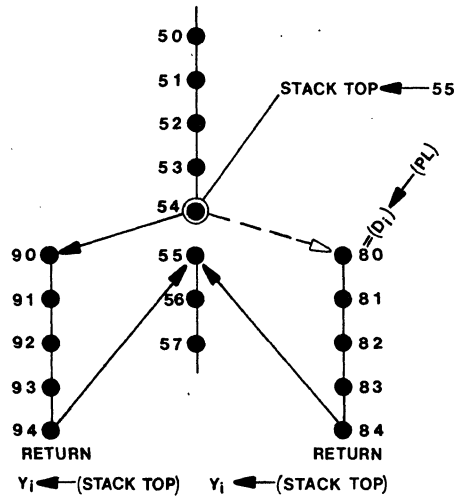


Figure 13. COND JSB R/PL (JSRP)

Control Instruction 6

CJV (Conditional Jump Vector) — This is a conditional jump control instruction. When CJV is executed, the VECT output is enabled and the next microinstruction address is taken from an address generator. The VECT line must control the TRI-STATE[®] enable line of a register, a buffer, or a PROM, containing the next microprogram address. This instruction provides one technique for performing interrupt type branching at the microprogram level. Since CJV is a conditional control instruction, passing the condition code inputs will allow the vector source address to pass through the IDM2910A. If the condition code test fails the next sequential address will be taken from the address register.

As shown in Figure 14, if CJV is at location 52, and the condition code test passes, microprogram execution will jump to vector address 20 and continue. If the condition code test fails, microprogram execution will continue at address 53.

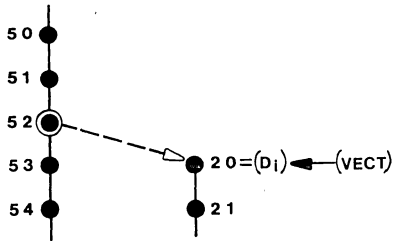


Figure 14. COND JUMP VECTOR (CJV)

Control Instruction 7

JRP (Conditional Jump) — This control instruction is a conditional jump to another routine via the contents of either the register/counter or the pipeline register. JRP is similar to JSRP (control instruction 5), except that no push onto the stack is performed for JRP.

The example shown in Figure 15 shows JRP as a branch to one of two addresses, depending upon the results of the condition code test. Assume the pipeline register contains an address value of 70 when the contents of address 52 are being executed. As the contents of address 53 are clocked into the pipeline register, the address value of 70 is loaded into the register/counter. If the address value of 80 is available when the contents of address 53 are in the pipeline register, either address 70 or address 80 will be passed through the IDM2910A, depending upon the results of the condition code test.

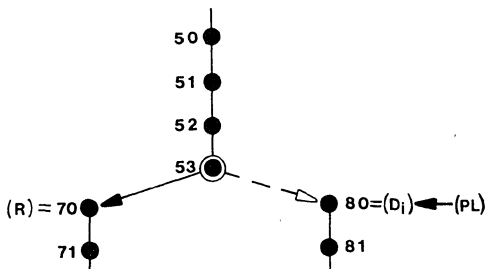


Figure 15. COND JUMP R/PL (JRP)

Control Instruction 8

RFCT (Repeat Loop, Counter Not Equal to Zero) — This control instruction uses the decrementing ability of the register/counter to loop on one or more microinstructions. A preceding instruction, such as PUSH, must have loaded a count value into the register/counter while pushing the next address onto the stack. RFCT tests the register/counter for a non-zero value. If the counter is non-zero, the register/counter is decremented by one and the address of the next instruction is taken from the top of the stack. This sequence will repeat until the register/counter equals zero (the exit condition has

been met), causing the next sequential address to be selected ($Y_i = \mu AR$). The stack is popped since looping back is not required anymore.

As shown in Figure 16, a PUSH control instruction would most likely be at address 50. The PUSH will cause address 51 to be pushed onto the stack and will load the register/counter with the count value contained in the pipeline register branch address field.

For this example, the loop test is made at the end of the loop routine (address 54), so the value loaded into the register/counter must be one less than the desired number of passes through the loop. Using the method in the example, a loop may be executed from 1 to 4096 times.

The ability to perform single-microinstruction loops is an efficient way to execute the same microinstruction a specified number of times. Examples are fixed rotates, byte swap, fixed point multiply, and fixed point divide.

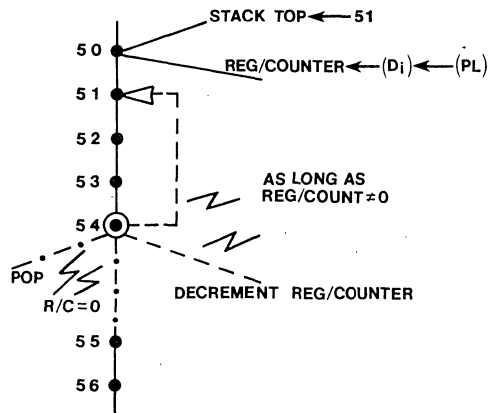


Figure 16. REPEAT LOOP, CNTR ≠ 0 (RFCT)

Control Instruction 9

RPCT (Repeat Pipeline Register, Counter Not Equal to Zero) — This control instruction uses the decrementing ability of the register/counter to loop on one or more microinstructions. RPCT is similar to control instruction RFCT (control instruction 8) except the branch address is taken from the pipeline register whereas RFCT takes it from the file. As long as the register/counter is not zero, RPCT will decrement the value in the register/counter and branch to the address taken from the pipeline register through the D_i inputs. Once the register/counter equals zero, the next address will be selected ($Y_i = \mu AR$). For some cases, this control instruction can be considered to be a one-word extension of the stack. By using RPCT, a microprogram loop using the register/counter can be executed, even though the stack may be completely full. A preceding control instruction must have loaded a count value into the register/counter. RPCT does not perform a pop operation because the stack is not being used.

As shown in Figure 17, microinstruction 51 could be Load Counter and Continue (LDCT, control instruction 12). RPCT is the control instruction at 52 and is shown as a single microinstruction loop. The address in the

pipeline register would be 52. Although a single microinstruction loop is shown, by changing the address in the pipeline register, multi-instruction loops may be performed for a fixed number of times.

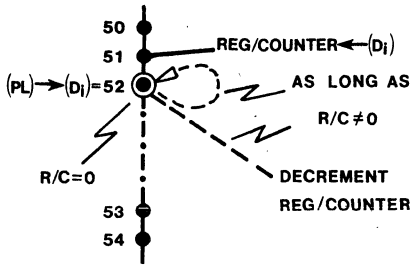


Figure 17. REPEAT PL, CNTR ≠ 0 (RPCT)

Control Instruction 10

CRTN (Conditional Return-from-Subroutine) — This control instruction is used to return from a microsubroutine to the control instruction immediately following the microsubroutine call. CRTN is a conditional return, with the return occurring only if the condition code test passes. If the condition code test fails, the next sequential microinstruction will be executed.

As shown in Figure 18, the use of CRTN is illustrated for both the conditional and the unconditional modes. A Jump-to-Subroutine control instruction is executed at address 52, pushing return address 90 onto the stack and transferring control to address 90. A CRTN is executed at address 93. If the condition code test passes, the microprogram returns to address 53 and the stack is popped. If the condition code test fails, execution continues through to address 97, where the microsubroutine is considered complete. CRTN must now be executed unconditionally. The microinstruction at address 97 is programmed to force \overline{CCEN} high, disabling the condition code test, with the forced pass causing an unconditional return.

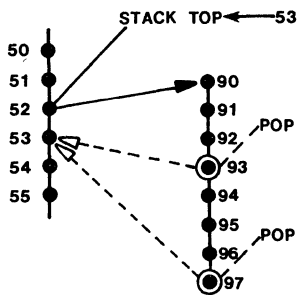


Figure 18. COND RETURN (CRTN)

Control Instruction 11

CJPP (Conditional Jump Pipeline Register Address and Pop Stack) — This control instruction provides another method of loop termination and stack maintenance. CJPP is a conditional jump, with the jump occurring only if the condition code test passes. A stack pop will also occur since this jump terminates the loop (whose branch address is located in the stack top).

As shown in Figure 19, a return address is pushed onto the stack and is followed by a short loop. The microinstructions at addresses 52, 53, and 54 are all CJPP control instructions. At address 52, if the condition code test passes, a branch to address 70 and a stack pop will occur. If the condition code test fails, the next sequential address (address 53) will be selected. The same conditions exist for the microinstructions at addresses 53 and 54, with 53 pointing to either address 90 or address 54, and 54 pointing to either address 80 or address 55. Used in this sort of loop, the CJPP control instruction is very useful when several inputs require testing before proceeding to other instructions. This provides the powerful jump-table programming technique at the microprogram level.

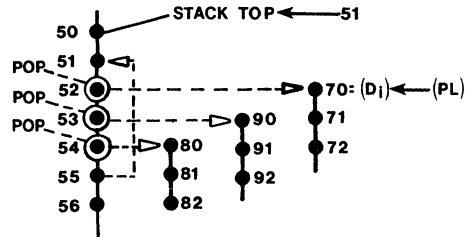


Figure 19. COND JUMP PL & POP (CJPP)

Control Instruction 12

LDCT (Load Counter and Continue) — This control instruction enables the register/counter to be loaded with the value present on the direct input lines. The direct input lines are normally connected to the pipeline register branch address field. For the architecture discussed here, the microinstruction under execution will supply either a branch address or a count value to the register/counter.

There are three methods for loading the register/counter:

1. The conditional load using the PUSH control instruction (number 4).
2. The use of the \overline{RLD} input in conjunction with any of the control instructions.
3. The explicit load using LDCT.

When using \overline{RLD} in conjunction with any other control instruction, any counting or decrementing called for is overridden and a load into the register/counter occurs. The \overline{RLD} input provides additional microinstruction power at the expense of one bit of microinstruction width. LDCT is the exact equivalent of using \overline{RLD} with control microinstruction 14 (CONT). LDCT provides the ability to load the register/counter for those systems in which \overline{RLD} is not under microprogram control.

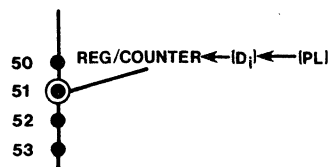


Figure 20. LD CNTR & CONTINUE (LDCT)

Control Instruction 13

LOOP (Test-End-of-Loop) — This control instruction provides a way of conditionally exiting a loop from the bottom. Prior to entering the loop, a branch address must be pushed onto the stack. LOOP will continue to branch back to the address contained on the top of the stack as long as the condition code test fails. When the condition code test passes, the next sequential address is selected ($Y_1 = \mu AR$) and the stack is popped.

As shown in Figure 21, the branch address is pushed onto the stack and then the microprogram enters the loop. LOOP is located at address 56. If the condition code test fails, the branch address 52 will be taken from the stack and the program loops to address 52. If the condition code test passes, the loop will terminate and the microinstruction at the next sequential address (taken from the address register) will be executed. Address 52 is popped from the stack once the condition code test passes, thereby performing the required stack maintenance.

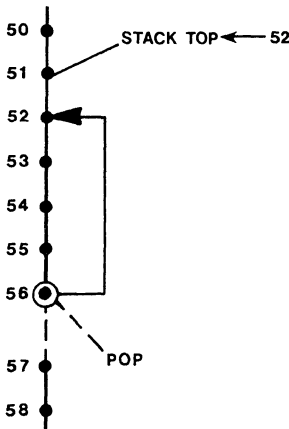


Figure 21. TEST END LOOP (LOOP)

Control Instruction 14

CONT (Continue) — This control instruction increments the address register so the next sequential microinstruction can be executed. CONT should be the default control instruction requested by the firmware when no other control instruction needs performing.

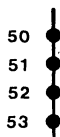


Figure 22. CONTINUE (CONT)

Control Instruction 15

TWB (Three-Way Branch) — This control instruction is the most complex of the 16 IDM2910A control instructions. TWB is a conditional control instruction that can test either the condition code input or the register/counter contents to determine the next branch address.

A preceding control instruction, such as a PUSH, must have loaded a count value into the register/counter while pushing the loop branch address onto the stack. As long as the condition code test fails, and the register/counter is not zero, the branch will be to the address on the top of the stack and the register/counter will be decremented. If the register/counter reaches zero, the next branch address is taken from the pipeline register (via the direct input lines). If at any time during the execution of TWB the condition code passes, no branch will occur and the next sequential address will be selected ($Y_1 = \mu AR$). Once the loop is exited, for either reason, the stack is popped.

The three-way branch can enhance system performance in a number of ways. Some examples are:

1. Performing a memory search that is terminated either by finding the desired value or by reaching the search limit.
2. Terminating a variable-field-length arithmetic operation upon finding that the contents of the unprocessed portion of the field are all zeros.
3. Performing a key search in a disc controller that is processing variable-length records.
4. Normalizing a floating-point number.

An example of a memory search operation is shown in Figure 23. A PUSH is executed at address 63 to push the return address 64 onto the stack, and to load a count value into the register/counter. The count value must be one less than the number of memory locations to be searched prior to exiting the loop. Address 64 contains a microinstruction that fetches a value from the next memory area to be searched, and compares it with the search key. A test for the results of the search comparison is at address 65. Address 65 also contains TWB for microprogram control. If matching does not occur, the condition code test fails and the microprogram loops back to address 64 to obtain the next search address. Once the register/counter equals zero, the microprogram will branch the branch address (address 72) taken from the pipeline register. If a match is found during the search, the condition code test will pass during the TWB control instruction and the next sequential address will be taken from the address register. Regardless of which method of exiting the loop is used, the stack will be popped and the loop branch address removed from the top of the stack.

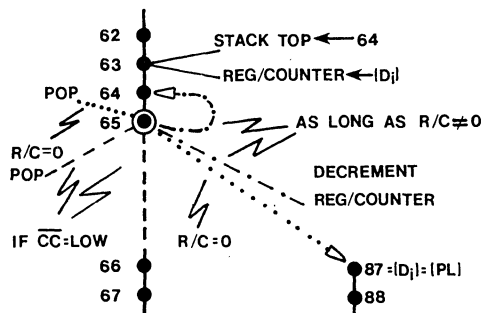


Figure 23. THREE-WAY BRANCH (TWB)

Ordering Information

Package Type	Package Number	Temperature Range	Order Number
Molded DIP	N40A	0°C to +70°C	IDM2910ANC
Hermetic DIP	D40C	0°C to +70°C	IDM2910AJC
Hermetic DIP	D40C	-55°C to +125°C	IDM2910AJM
Hermetic DIP	D40C	-55°C to +125°C	IDM2910AJM/883

IDM29803 16-Way Branch Controller

General Description

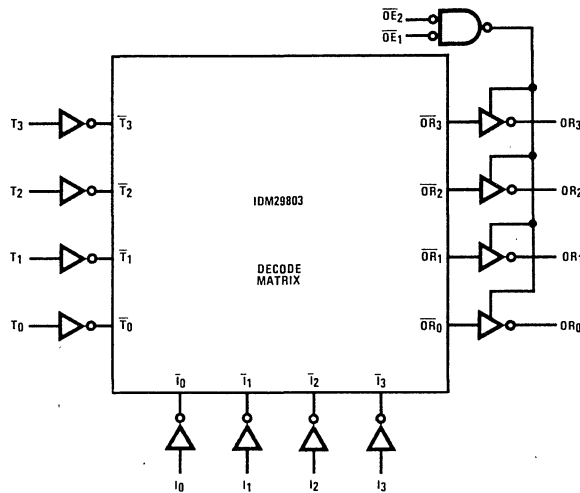
When used in conjunction with the IDM2909A address controller, the IDM29803 provides 16-way branch control. Four different inputs can be tested simultaneously by the 16 instructions of the IDM29803; thus, the four OR inputs of the IDM2909A can be driven by the four outputs of the IDM29803 and a branch can be made to any one of the 16 addresses.

If one test (T) input is being tested, the device will select one of two possible addresses; if two inputs are being tested, the device will select one of four possible addresses and, if three inputs are being tested, one of eight addresses will be selected. If all four inputs are tested, one of sixteen addresses is selected as the field used to drive the OR inputs of the IDM2909A. The "zero" instruction serves as a test inhibit function.

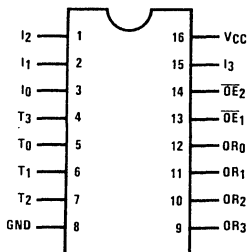
Features and Benefits

- 16 separate instructions — 2-, 4-, 8-, or 16-way branch in one microprogram execution cycle
- Four discrete test inputs
- Four discrete outputs for driving the four OR inputs of the IDM2909A address controller
- Provides a maximum branching capability in a microprogram control unit using the IDM2909A
- Uses low-power Schottky technology
- Meets all requirements of MIL-STD-883

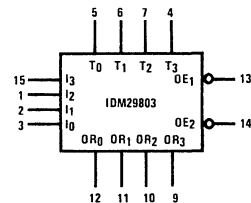
Logic Diagram



Connection Diagram



Logic Symbol



Absolute Maximum Ratings (Note 1)

Storage Temperature	-65°C to +125°C
Temperature (Ambient) Under Bias	-55°C to +125°C
Supply Voltage to Ground Potential	-0.5V to +7.0V
DC Voltage Applied to Outputs for High Output State	-0.5V to +V _{CC} max
DC Input Voltage	-0.5V to +5.5V
DC Output Current, into Outputs	30 mA
DC Input Current	-30 mA to +5.0 mA

Operating Range

P/N	Ambient Temperature	V _{CC}
Com'1 IDM29803DC, NC	0°C to +70°C	4.75 V to 5.25 V
Mil IDM29803DM, DM/883	-55°C to +125°C	4.50 V to 5.50 V

DC Electrical Characteristics (Note 2)

PARAMETER	CONDITIONS	Com'1			Mil			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
I _F	Input Load Current, All Inputs V _{CC} = Max, V _F = 0.45V		-80	-250		-80	-250	μA
I _R	Input Leakage Current, All Inputs V _{CC} = Max, V _R = 2.7V			25			25	μA
I _{RB}	Input Leakage Current, All Inputs V _{CC} = Max, V _{RB} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage V _{CC} = Min, I _{OL} = 16 mA		0.35	0.45		0.35	0.5	V
V _{IL}	Low Level Input Voltage			0.80			0.80	V
V _{IH}	High Level Input Voltage	2.0			2.0			V
I _{CEX}	Output Leakage Current (Open-Collector Only) V _{CC} = Max, V _{CEX} = 2.4V V _{CC} = Max, V _{CEX} = 5.5V			50			50	μA
				100			100	μA
V _C	Input Clamp Voltage V _{CC} = Min, I _{IN} = -18 mA		-0.8	-1.2		-0.8	-1.2	V
C _{IN}	Input Capacitance V _{CC} = 5V, V _{IN} = 2V, T _A = 25°C, 1 MHz		4.0			4.0		pF
C _O	Output Capacitance V _{CC} = 5V, V _O = 2V, T _A = 25°C, 1 MHz, Output "OFF"		6.0			6.0		pF
I _{CC}	Power Supply Current V _{CC} = Max, All Inputs Grounded, All Outputs Open		80	130		80	130	mA

TRI-STATE PARAMETERS

I _{SC}	Output Short Circuit Current V _O = 0V, V _{CC} = Max, (Note 3)	-30	-60	-100	-30	-60	-100	mA
I _{HZ}	Output Leakage (TRI-STATE) V _{CC} = Max, V _O = 0.45 to 2.4V, Chip Disabled			±50			±50	μA
V _{OH}	Output Voltage High I _{OH} = -2 mA I _{OH} = -6.5 mA				2.4	3.2		V
		2.4	3.2					V

AC Electrical Characteristics (With standard load)

PARAMETER	CONDITIONS	Com'1			Mil			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
t _{AA}	Address Access Time (Figure 1)	10	35	50	10	35	60	ns
t _{EA}	Enable Access Time (Figure 2)	5	15	25	5	15	30	ns
t _{ER}	Enable Recovery Time (Figure 2)	5	15	25	5	15	30	ns

Note 1: Absolute maximum ratings are those values beyond which the device may be permanently damaged. They do not mean that the device may be operated at these values.

Note 2: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5V and T_A = 25°C.

Note 3: During I_{SC} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

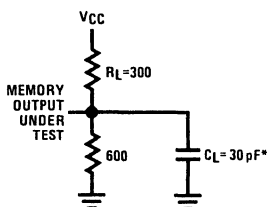
Switching Characteristics Over Operating Range

Symbol	Description	Test Conditions	Com'l		Mil		Units
			Min	Max	Min	Max	
t _{PLH}	I _j to OR _i	C _L = 15 pF R _L = 2.0 kΩ		50		60	ns
t _{PHL}	I _j to OR _i						
t _{PLH}	T _j to OR _i			50		60	ns
t _{PHL}	T _j to OR _i						
t _{ZH}	OE _i to OR _i			25		30	ns
t _{ZL}	OE _i to OR _i						
t _{HZ}	OE _i to OR _i			25		30	ns
t _{LZ}	OE _i to OR _i						

Definition of Functional Terms

I ₀ , I ₁ , I ₂ , I ₃	The four instruction inputs to the device
T ₀ , T ₁ , T ₂ , T ₃	The four test inputs for the device
OR ₀ , OR ₁ , OR ₂ , OR ₃	The four outputs of the device that are connected to the four OR inputs of the IDM2909A
\overline{OE}_1 , \overline{OE}_2	Output Enable. When either \overline{OE} input is High, the OR _i outputs are in the high impedance state. When both the \overline{OE}_1 and \overline{OE}_2 inputs are Low, the OR outputs are enabled and the selected data will be present.

Standard Test Load



*C_L includes probe and jig capacitance

- Input waveforms are supplied by a pulse generator having the following characteristics: PRR = 1 MHz, Z_{OUT} = 50 Ω, t_r ≤ 2.5 ns and t_f ≤ 2.5 ns (between 1.0V and 2.0V).
- t_{AA} is measured with both enable inputs at a steady low level.
- t_{EA} and t_{ER} are measured from the 1.5V on inputs and outputs with all address inputs at a steady level and with the unused enable input at a steady low level.

Switching Time Waveforms

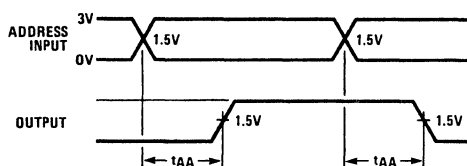


Figure 1. Address Access Time

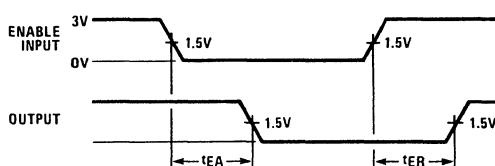


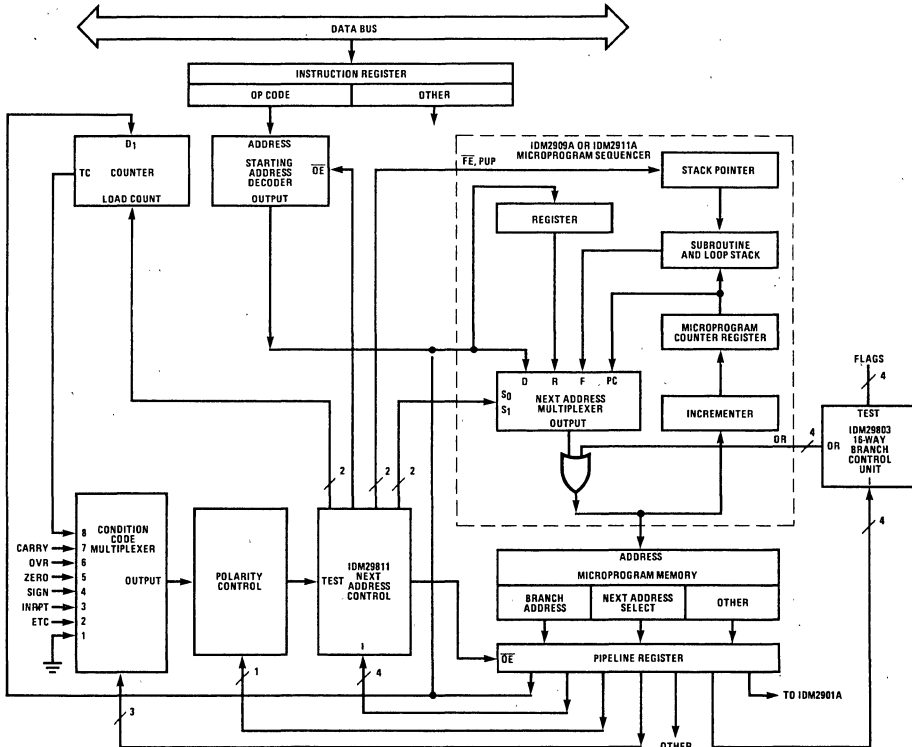
Figure 2. Enable Access Time and Recovery Time

Guaranteed Loading Rules Over Operating Range (In Unit Loads)

A Low-Power Schottky TTL Unit Load is defined as 20 μ A measured at 2.7V High and -0.36mA measured at 0.4V Low.

Pin Nos.	Input/ Output	Input Load	Output High	Output Low
1	I ₂	0.5	—	—
2	I ₁	0.5	—	—
3	I ₀	0.5	—	—
4	T ₃	0.5	—	—
5	T ₀	0.5	—	—
6	T ₁	0.5	—	—
7	T ₂	0.5	—	—
8	GND	—	—	—
9	OR ₃	—	100	44
10	OR ₂	—	100	44
11	OR ₁	—	100	44
12	OR ₀	—	100	44
13	OE ₁	0.5	—	—
14	OE ₂	0.5	—	—
15	I ₃	0.5	—	—
16	VCC	—	—	—

Applications Example



Note: The least significant microprogram sequencer is an IDM2909A and the more significant sequencers are IDM2911A's.

A Typical Computer Control Unit Using the IDM2909A, IDM2911A, IDM29803 and IDM29811.

Function Table

Function	I ₃	I ₂	I ₁	I ₀	T ₃	T ₂	T ₁	T ₀	OR ₃	OR ₂	OR ₁	OR ₀
No Test	L	L	L	L	X	X	X	X	L	L	L	L
Test T ₀	L	L	L	H	X	X	X	L	L	L	L	L
Test T ₁	L	L	H	L	X	X	L	X	L	L	L	L
Test T ₀ & T ₁	L	L	H	H	X	X	L	L	L	L	L	L
Test T ₂	L	H	L	L	X	L	X	X	L	L	L	L
Test T ₀ & T ₂	L	H	L	H	X	L	X	L	L	L	L	L
Test T ₁ & T ₂	L	H	H	L	X	L	L	X	L	L	L	L
Test T ₀ , T ₁ , & T ₂	L	H	H	H	X	L	L	L	L	L	L	L
Test T ₃	H	L	L	L	L	X	X	X	L	L	L	L
Test T ₀ & T ₃	H	L	L	H	L	X	X	L	L	L	L	L
Test T ₁ & T ₃	H	L	H	L	L	X	L	X	L	L	L	L
Test T ₀ , T ₁ , & T ₃	H	L	H	H	L	X	L	L	L	L	L	L
Test T ₂ & T ₃	H	H	L	L	L	L	X	X	L	L	L	L
Test T ₀ , T ₂ , & T ₃	H	H	L	H	L	L	X	L	L	L	L	L
Test T ₁ , T ₂ , & T ₃	H	H	H	L	L	L	L	X	L	L	L	L
Test T ₀ , T ₁ , T ₂ , & T ₃	H	H	H	H	L	L	L	L	L	L	L	L

Ordering Information

Package Type	Package Number	Temperature Range	Order Number
Molded DIP	N16A	0°C to +70°C	IDM29803NC
Hermetic DIP	J16A (D16C)	0°C to +70°C	IDM29803JC
Hermetic DIP	J16A (D16C)	-55°C to +125°C	IDM29803JM
Hermetic DIP	J16A (D16C)	-55°C to +70°C	IDM29803JM/883

IDM29811 Next-Address Controller

General Description

The IDM29811 next-address control unit is specifically designed for next address control of the IDM2911A sequencer. The device can be used in high-performance computer control systems, structured state machine designs, or in other applications that utilize microprogramming techniques.

A 4-bit instruction field (I_3-I_0) provides sixteen instructions; also, a test input is available for conditional instructions. Among the conditional instructions that can be executed are: conditional jumps, conditional jump to subroutine, conditional return from subroutine, conditional repeat loops, conditional branch to starting address, and so on.

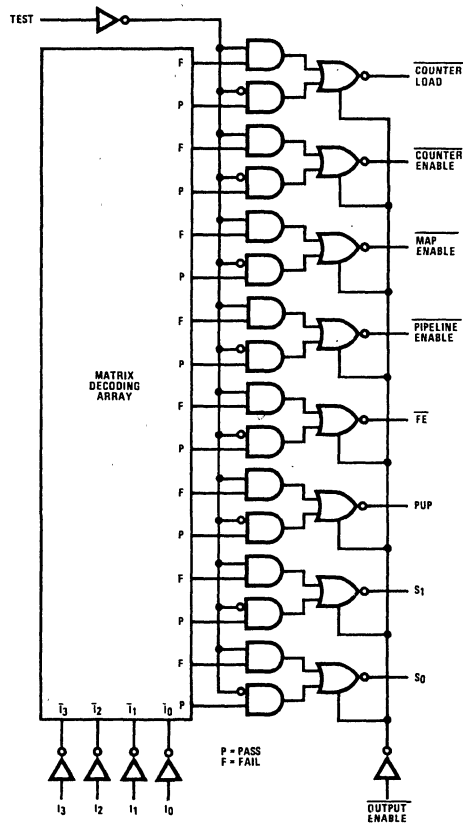
A single IDM29811 can be used to control any number of IDM2911A sequencers. Using one IDM29811 and

three IDM2911As, a sequencer capable of controlling 4k of microprogram memory can be easily implemented.

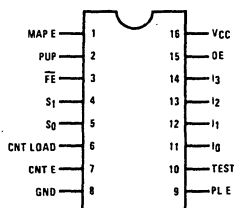
Features and Benefits

- 16 next-address instructions
- Test input for conditional instructions
- Separate outputs to control the IDM2911A, an independent event counter, and a mapping PROM/branch address interface
- Uses low-power Schottky technology
- Meets all requirements of MIL-STD-883

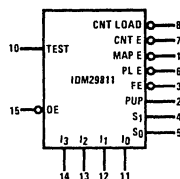
Logic Diagram



Connection Diagram



Logic Symbol



Absolute Maximum Ratings (Note 1)

Storage Temperature	-65°C to +150°C
Temperature (Ambient) Under Bias	-55°C to +125°C
Supply Voltage to Ground Potential	-0.5V to +6.3V
DC Voltage Applied to Outputs for High Output State	-0.5V to +V _{CC} max
DC Input Voltage	-0.5V to +5.5V
DC Output Current, into Outputs	30 mA
DC Input Current	-30 mA to +5.0 mA

Operating Range

P/N	Ambient Temperature	V _{CC}
Com'l IDM29811JC,NC	0°C to +70°C	4.75V to 5.25V
Mil IDM29811JM, JM/883	-55°C to +125°C	4.50V to 5.50V

DC Electrical Characteristics (Note 2)

PARAMETER		CONDITIONS	Com'l			Mil			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
I _{IL}	Input Load Current, All Inputs	V _{CC} = Max, V _{IN} = 0.45V		-80	-250		-80	-250	μA
I _{IH}	Input Leakage Current, All Inputs	V _{CC} = Max, V _{IN} = 2.7V			25			25	μA
I _I	Input Leakage Current, All Inputs	V _{CC} = Max, V _{IN} = 5.5V			1.0			1.0	mA
V _{OL}	Low Level Output Voltage	V _{CC} = Min, I _{OL} = 16 mA		0.35	0.5		0.35	0.5	V
V _{IL}	Low Level Input Voltage				0.80			0.80	V
V _{IH}	High Level Input Voltage		2.0			2.0			V
V _C	Input Clamp Voltage	V _{CC} = Min, I _{IN} = -18 mA		-0.8	-1.2		-0.8	-1.2	V
C _{IN}	Input Capacitance	V _{CC} = 5V, V _{IN} = 2V, T _A = 25°C, 1 MHz		4.0			4.0		pF
C _O	Output Capacitance	V _{CC} = 5V, V _O = 2V, T _A = 25°C, 1 MHz, Output "OFF"		6.0			6.0		pF
I _{CC}	Power Supply Current	V _{CC} = Max, All Inputs Grounded, All Outputs Open		70	110		70	110	mA

TRI-STATE PARAMETERS

I _{SC}	Output Short Circuit Current	V _O = 0V, V _{CC} = Max, (Note 3)	-20	-45	-70	-20	-45	-70	mA
I _{HZ}	Output Leakage (TRI-STATE)	V _{CC} = Max, V _O = 0.45 to 2.4V, Chip Disabled			±50			±50	μA
V _{OH}	Output Voltage High,	I _{OH} = -2 mA				2.4	3.2		V
		I _{OH} = -6.5 mA	2.4	3.2				V	

Note 1: Absolute maximum ratings are those values beyond which the device may be permanently damaged. They do not mean that the device may be operated at these values.

Note 2: These limits apply over the entire operating range unless stated otherwise. All typical values are for V_{CC} = 5V and T_A = 25°C.

Note 3: During I_{SC} measurement, only one output at a time should be grounded. Permanent damage may otherwise result.

Switching Characteristics Over Operating Temperature

Symbol	Description	Test Conditions	Com'l		Mil		Units
			Min.	Max.	Min.	Max.	
t _{PLH}	I _i to Any Output	C _L = 15 pF R _L = 2.0 kΩ		30		40	ns
t _{PHL}							
t _{PLH}	Test to Any Output			30		40	ns
t _{PHL}							
t _{ZH}	OE to Any Output			20		30	ns
t _{ZL}							
t _{HZ}	OE to Any Output			20		30	ns
t _{LZ}							

Pinout Descriptions

I ₃ /I ₂ /I ₁ /I ₀	Four instruction inputs	S ₀ /S ₁	These outputs are used to drive the S ₀ /S ₁ inputs of the IDM2911A address controller. These outputs control whether the direct input, the register, the microprogram counter, or the stack is selected as the source of the next address for the microprogram memory.
Test	Condition-code input. When test input is low, the device assumes test has failed; when input is high, the test is assumed to have passed. In either case, a branch is made to one of the conditional-code instructions; refer to the tables which follow.		
Counter Load	An output used to drive the parallel load input of an up/down counter.		
Counter Enable	An output used to drive the enable input of an up/down counter.		
Map Enable	An output that controls the three-state outputs of the mapping PROM or PLA used to provide the initial starting address for each machine instruction.		
Pipeline Enable	An output used to control the three-state output of the pipeline register which contains the branch address of the computer control unit.		
FE File Enable	An output used to drive the file enable input of the IDM2911A. When this output is low, a stack operation will take place.		
PUP	An output used to drive the push/pop input of the IDM2911A address controller. When the PUP output is high, a push will take place if the file is enabled. When the PUP output is low, a pop will take place if the file is enabled.		

Instruction Table

Mnemonic	I ₃	I ₂	I ₁	I ₀	Instruction
JZ	L	L	L	L	Jump to Address Zero
CJS	L	L	L	H	Conditional Jump-to-Subroutine with Jump Address in Pipeline Register
JMAP	L	L	H	L	Jump to Address at Mapping PROM Output
CJP	L	L	H	H	Conditional Jump to Address in Pipeline Register
PUSH	L	H	L	L	Push Stack and Conditionally Load Counter
JSRP	L	H	L	H	Jump-to-Subroutine with Starting Address Conditionally Selected from IDM2911A Register or Pipeline Register
CJV	L	H	H	L	Conditional Jump to Vector Address
JRP	L	H	H	H	Jump to Address Conditionally Selected from IDM2911A R-Register or Pipeline Register
RFCT	H	L	L	L	Repeat Loop if Counter is Not Equal to Zero
RPCT	H	L	L	H	Repeat Pipeline Address if Counter is Not Equal to Zero
CRTN	H	L	H	L	Conditional Return-from-Subroutine
CJPP	H	L	H	H	Conditional Jump to Pipeline Address and Pop Stack
LDCT	H	H	L	L	Load Counter and Continue
LOOP	H	H	L	H	Test End of Loop
CONT	H	H	H	L	Continue to Next Address
JP	H	H	H	H	Jump to Pipeline Register Address

Function Table

Mnemonic	Inputs				Function	Test Input	Outputs				
	I ₃	I ₂	I ₁	I ₀			Next ADDR Source	File	Counter	MAP E	PL E
JZ	L	L	L	L	JUMP ZERO	K	D	HOLD	LL*	H	L
CJS	L	L	L	H	COND JSB PL	L H	PC D	HOLD PUSH	HOLD HOLD	H H	L L
JMAP	L	L	H	L	JUMP MAP	X	D	HOLD	HOLD	L	H
CJP	L	L	H	H	COND JUMP PL	L H	PC D	HOLD HOLD	HOLD HOLD	H H	L L
PUSH	L	H	L	L	PUSH/COND LD CNTR	L H	PC PC	PUSH PUSH	HOLD LOAD	H H	L L
JSRP	L	H	L	H	COND JSB R/PL	L H	R D	PUSH PUSH	HOLD HOLD	H H	L L
CJV	L	H	H	L	COND JUMP VECTOR	L H	PC D	HOLD HOLD	HOLD HOLD	H H	H H
JRP	L	H	H	H	COND JUMP R/PL	L H	R D	HOLD HOLD	HOLD HOLD	H H	L L
RFCT	H	L	L	L	REPEAT LOOP, CNTR ≠ 0	L H	F PC	HOLD POP	DEC HOLD	H H	L L
RPCT	H	L	L	H	REPEAT PL, CNTR ≠ 0	L H	D PC	HOLD HOLD	DEC HOLD	H H	L L
CRTN	H	L	H	L	COND RTN.	L H	PC F	HOLD POP	HOLD HOLD	H H	L L
CJPP	H	L	H	H	COND JUMP PL & POP	L H	PC D	HOLD POP	HOLD HOLD	H H	L L
LDCT	H	H	L	L	LOAD CNTR & CONTINUE	X	PC	HOLD	LOAD	H	L
LOOP	H	H	L	H	TEST END LOOP	L H	F PC	HOLD POP	HOLD HOLD	H H	L L
CONT	H	H	H	L	CONTINUE	X	PC	HOLD	HOLD	H	L
JP	H	H	H	H	JUMP PL	X	D	HOLD	HOLD	H	L

L = Low DEC = Decrement
H = High *LL = Special Case
X = Don't Care

Truth Table

Mnemonic	Function	Pin No.												
		Inputs					Outputs							
		I ₃	I ₂	I ₁	I ₀	TEST	Next ADDR Source S ₁ S ₀		File FE PUP		Counter LOAD EN		MAP E	PL E
JZ	JUMP ZERO	L	L	L	L	L	H	H	H	H	L	L	H	L
CJS	COND JSB PL	L	L	L	H	L	L	L	H	H	H	H	H	L
JMAP	JUMP MAP	L	L	H	L	L	H	H	H	H	H	H	L	H
CJP	COND JUMP PL	L	L	H	H	L	L	L	H	H	H	H	H	L
PUSH	PUSH/COND LD CNTR	L	H	L	L	L	L	L	L	H	H	H	H	L
JSRP	COND JSB R/PL	L	H	L	H	L	L	H	L	H	H	H	H	L
CJV	COND JUMP VECTOR	L	H	H	L	L	L	L	H	H	H	H	H	H
JRP	COND JUMP R/PL	L	H	H	H	L	L	H	H	H	H	H	H	L
RFCT	REPEAT LOOP, CTR ≠ 0	H	L	L	L	L	H	L	H	L	H	L	H	L
RPCT	REPEAT PL, CTR ≠ 0	H	L	L	H	L	H	H	H	H	H	L	H	L
CRTN	COND RTN	H	L	H	L	L	L	L	H	L	H	H	H	L
CJPP	COND JUMP PL & POP	H	L	H	H	L	L	L	H	L	H	H	H	L
LDCT	LD CNTR & CONTINUE	H	H	L	L	L	L	L	H	H	L	H	H	L
LOOP	TEST END LOOP	H	H	L	H	L	H	L	H	L	H	H	H	L
CONT	CONTINUE	H	H	H	L	L	L	L	H	H	H	H	H	L
JP	JUMP PL	H	H	H	H	L	H	H	H	H	H	H	H	L

L = Low, H = High

Guaranteed Loading Characteristics Over Operating Range (in unit loads)

Pin Nos.	Input/Output	Input Load	Output High	Output Low
1	MAP E	—	100	44
2	PUP	—	100	44
3	FE	—	100	44
4	S ₁	—	100	44
5	S ₀	—	100	44
6	CNT LOAD	—	100	44
7	CNT E	—	100	44
8	GND	—	—	—
9	PL E	—	100	44
10	TEST	0.5	—	—
11	I ₀	0.5	—	—
12	I ₁	0.5	—	—
13	I ₂	0.5	—	—
14	I ₃	0.5	—	—
15	OE	—	100	44
16	V _{CC}	—	—	—

A Low-Power Schottky TTL Unit Load is defined as 20 μ A measured at 2.7V High and -0.36mA measured at 0.4V Low.

DM10900 8-Bit Parity ALU Slice

General Description

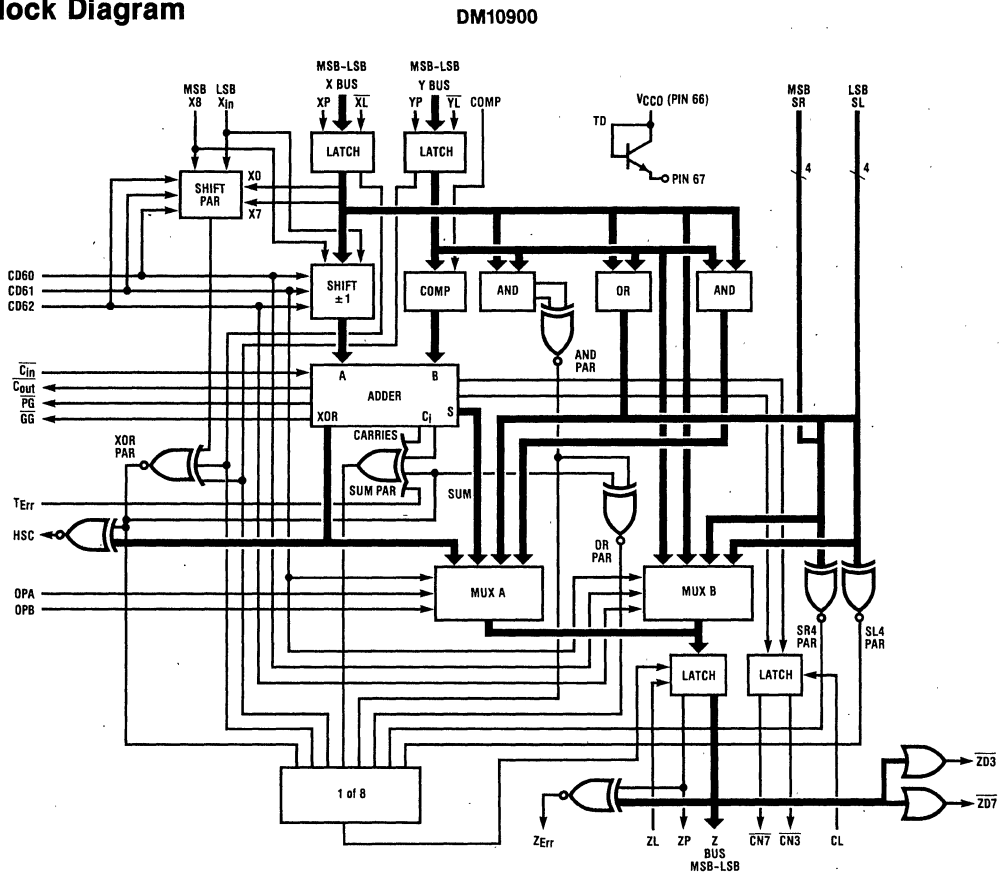
The DM10900 8-Bit Microprocessor slice is a cascadable device designed for use in high performance central processing units, microprogrammable controllers, and other applications where hardware/software flexibility, ease of expansion, and ECL 10k compatibility are system requirements. The building block architecture and microinstruction format of the DM10900 permits efficient emulation of most digital systems.

As shown in the block diagram below, the DM10900 consists of a parallel 8-bit adder accessed by two latched input ports. In addition, various logic operations can also be performed on the input data. Shifting circuits and parity detect circuits implemented with ECL, oxide-isolated technology, allow the device to function as a very powerful, high performance ALU.

Features

- Manufactured from high performance, oxide-isolated ECL macrocell array.
- Performs all necessary logic and arithmetic operations.
- Dual port architecture—two 8-bit, latched input ports; one 8-bit, latched output port.
- Internal look-ahead carry with propagate/generate outputs.
- Internal parity detect circuit with parity error output.
- Expandable in 4- or 8-bit increments to form larger word sizes.

Block Diagram



TL/L5014

Test Temperature

Symbol	0°C	+25°C	+70°C
$V_{IH\ max}$	-0.840	-0.810	-0.730
$V_{IHA\ min}$	-1.145	-1.105	-1.050
$V_{IL\ min}$	-1.95	-1.95	-1.95
$V_{ILA\ max}$	-1.490	-1.475	-1.450
V_{EE}	-5.2	-5.2	-5.2

(A) indicates the most positive value.

Recommended Operating Conditions

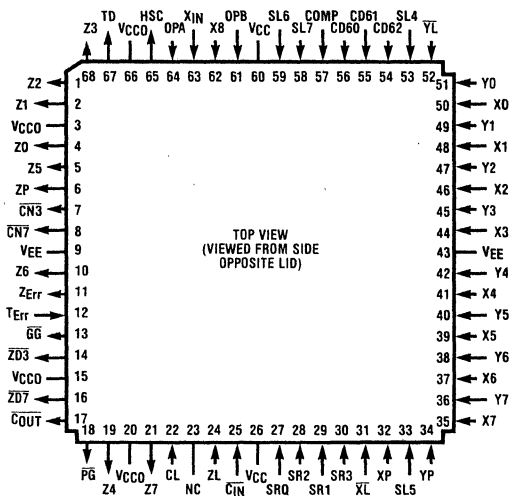
V_{EE}	Supply Voltage ($V_{CC} = 0V$)	-4.68 V_{DC} to -5.72 V_{DC}
T_A	Operating Temperature (Functional)	0 to +70°C
	Output Drive	50Ω to -2.0 V_{DC}
T_J	Junction Temperature	130°C Max.

Electrical Characteristics

Each ECL 10,000 series circuit has been designed to meet the DC specifications shown in the test table, after thermal equilibrium has been established. The circuit is in a test socket or mounted on a printed circuit board and transverse air flow greater than 1000 linear fpm is maintained. Outputs are terminated through a 50Ω resistor to -2.0V. Test procedures are shown for only one input, or for one set of input conditions. Other inputs are tested in the same manner.

Symbol	Parameters	Pin Under Test	DM10900 Test Limits							Voltage Applied to Pins Listed Below:					(V_{CC0}) (V_{CC}) Gnd	
			0°C		+25°C			+70°C		Unit	$V_{IH\ max}$	$V_{IL\ min}$	$V_{IHA\ min}$	$V_{ILA\ max}$		V_{EE}
			Min.	Max.	Min.	Typ.	Max.	Min.	Max.							
I_{EE}	Power Supply Drain Current	9, 43	514	855	514	685	855	514	855	mA_{DC}	—	—	—	—	9, 43	3, 15, 20 26, 60, 68
I_{INH}	Input Current CD61, $\bar{X}L$, $\bar{Y}L$, ZL , C_{IN} , OPA	55	—	600	—	—	600	—	600	μA_{DC}	—	—	—	—		
	All Others	50	—	250	—	—	250	—	250		50	—	—	—		
I_{INL}		50	0.5	—	0.5	—	—	0.5	—		—	50	—	—		
V_{OH}	Logic High Output Voltage	4	-1.000	-0.840	-0.960	—	-0.810	-0.905	-0.730	V_{DC}	50, 55, 24	31, 56, 54	—	—		
V_{OL}	Logic Low Output Voltage	4	-1.95	-1.665	-1.95	—	-1.650	-1.95	-1.625	V_{DC}	55, 24	50, 31, 56, 54	—	—		
V_{OHA}	Logic High Threshold Voltage	4	-1.02	—	-0.980	—	—	-0.925	—	V_{DC}	55, 24	31, 56, 54	50	—		
V_{OLA}	Logic Low Threshold Voltage	4	—	-1.645	—	—	-1.630	—	-1.605	V_{DC}	24, 55	31, 54, 56	—	50		

DM10900



TL/L5014

FIGURE 1. Input/Output Diagram

DM10900 Grid Array Package
Drawing Not Available at This Time

Table 1. Pin Assignments

Pin Description	Pin Number	Description	Pin Description	Pin Number	Description
X0	50	Input Bus — LSB Input	SL6	59	Shift Left Input to Z2
X1	48	Input Bus	SL7	58	Shift Left Input to Z3
X2	46	Input Bus	Z0	4	Output Bus — LSB Output
X3	44	Input Bus	Z1	2	Output Bus
X4	41	Input Bus	Z2	1	Output Bus
X5	39	Input Bus	Z3	68	Output Bus
X6	37	Input Bus	Z4	19	Output Bus
X7	35	Input Bus — MSB Input	Z5	5	Output Bus
X8	62	Shift Interconnect — MSB	Z6	10	Output Bus
XL	31	X Latch Control Bit	Z7	21	Output Bus — MSB Output
XP	32	X Input Parity Bit	ZD3	14	Zero Detect
XIN	63	Shift Interconnect — LSB	ZD7	16	Zero Detect
Y0	51	Input Bus — LSB Input	ZP	6	Parity Detect Output
Y1	49	Input Bus	ZL	24	Z Latch Control Bit
Y2	47	Input Bus	ZErr	11	Bus Error Detect Output
Y3	45	Input Bus	TErr	12	Test Error Input
Y4	42	Input Bus	Comp	57	Control Input Complement
Y5	40	Input Bus	CD60	56	Control Input
Y6	38	Input Bus	CD61	55	Control Input
Y7	36	Input Bus — MSB Input	CD62	54	Control Input
YL	52	Y Latch Control Bit	HSC	65	Half Sum Check Output
YP	34	Y Input Parity Bit	OPA	64	Control Input
CIN	25	Carry Input	OPB	61	Control Input
COUT	17	Carry Output	VEE	9	–5.2 Volt Supply
PG	18	Group Propagate Output	VEE	43	–5.2 Volt Supply
GG	13	Group Generate Output	VCC	26	Ground
Cn3	7	Detect System Overflow	VCC	60	Ground
Cn7	8	Detect System Overflow	VCC0	3	Ground
SR0	27	Shift Right Input to Z4	VCC0	66	Ground
SR1	29	Shift Right Input to Z5	VCC0	15	Ground
SR2	28	Shift Right Input to Z6	VCC0	20	Ground
SR3	30	Shift Right Input to Z7	VCC0	66	Ground
SL4	53	Shift Left Input to Z0	CL	22	Carry Latch Enable
SL5	33	Shift Left Input to Z1	NC	23	Not Used
			TD	67	Test Diode

Operation

The basic data input ports to the DM10900 are the X bus and Y bus, each capable of accepting eight data bits. To expand the word size of a DM10900 system, single-bit data paths C_{IN} , C_{OUT} , X_{IN} , and X8 along with 4-bit paths SL and SR are provided. In addition, group propagate and group generate outputs can be used with external carry look-ahead logic in an expanded system for faster operation.

The DM10900 outputs data on the Z bus and provides zero detect signals ZD7 for outputs Z7-Z4 and ZD3 for outputs Z3-Z0. In addition, carry signals $\overline{CN3}$ and $\overline{CN7}$ are generated within the adder determining overflow conditions. Parity circuitry continuously monitors data flow within the ALU slice and provides two error signals.

Each input and output port consists of eight data bits and one odd parity bit. The two input ports are latched and routed to four logic networks which generate a 1-bit shift right or left of X, a complement of Y, a logic OR of X and Y, and a logic AND of X and Y. The shift and complement circuits input to the adder network which provides the arithmetic sum and the logic exclusive-OR. Two 1-of-4 multiplexers select the data path to the Z output bus.

Pin Descriptions

- X Input Bus.** These eight data input pins serve as data paths to an internal latch in the ALU. Data is passed through the latch when Latch Control bit, \overline{XL} , is brought low and latched when \overline{XL} is brought high. X7 is the most significant bit (MSB) of the X input bus.
- Y Input Bus.** These eight data input pins operate identically to the X input bus described above. \overline{YL} is the latch control signal for the Y input bus.
- Parity Inputs, XP and YP.** To utilize the parity detect circuitry of the DM10900, parity for X input data and Y input data should be entered on the XP and YP inputs respectively. These bits are used in determining the Z parity output, ZP, and parity error signals, HSC and Z_{Err}.
- Shift Interconnects.** Shift interconnect signals X_{IN} , X8, SL and SR are provided to facilitate shift operations in cascaded slice systems.
For a single-bit shift left, X_{IN} is shifted into the X0 position and for a single-bit shift right, X8 is shifted into the X7 position. SL and SR are used for 4-bit shifts. For a shift left, SL7-SL4 are shifted into Z3-Z0 respectively, while the results of the OR circuit, $(X + Y)_3 - (X + Y)_0$ are shifted into Z7-Z4, respectively. For a shift right, SR3-SR0 are shifted into Z7-Z4, respectively, while the OR circuit outputs $(X + Y)_7 - (X + Y)_4$ are shifted into Z3-Z0, respectively.
- Half Sum Check.** HSC is a parity check of the X bus and Y bus along with an error check of the half sum adder network. HSC will detect a single-bit error or any combination of odd number of errors. Half sums are derived from the bit-by-bit Exclusive-OR of the two busses. The half sum bits, along with the input parity bits XP and YP, determine HSC as follows:

$$HSC = HS7 \oplus GS6 \oplus HS5 \oplus HS4 \oplus HS3 \oplus HS2 \oplus HS1 \oplus HS0 \oplus XP \oplus YP \oplus \text{Shift PAR}$$

- Carry Signals.** System overflow can be detected by the carry signals $\overline{CN3}$ and $\overline{CN7}$. Overflow occurs when the maximum system word or byte value has been exceeded. Only the overflow from the most significant 8-bit slice is used in a typical system.

Overflow is detected by the exclusive-OR of the carry out and carry in of the most significant bit in a system. In an 8-bit increment system (8, 16, 24, etc.) overflow can be generated by the exclusive-OR of C_{OUT} and $\overline{CN7}$. In a 4-bit increment system (4, 12, 16, etc.) overflow can be generated by the Exclusive-NOR of Z4 and $\overline{CN3}$ ($OF = Z4 \oplus \overline{CN3}$). Z4 is effectively the carry out of the 8-bit slice operating in a 4-bit slice mode.

Carry in, $\overline{C_{IN}}$, is used to interconnect 8-bit slices in a system. In a ripple carry mode, $\overline{C_{IN}}$ is connected to the carry out, C_{OUT} , of the previous slice. C_{OUT} occurs when the calculated value within the ALU exceeds the maximum capacity, a binary count over 255. C_{OUT} is generated by look-ahead carry logic in the 8-bit ALU.

- Output Z Bus.** These eight data output pins connect the output data latch to the external system. Data passes through the latch to the Z bus when ZL is high. Z7 is the most significant output bit.
- Zero Detect.** $\overline{ZD7}$ and $\overline{ZD3}$ indicate all lows on output latch Z7-Z4 and Z3-Z0, respectively. These outputs go low when their corresponding output bits are all low.
- Z Bus Error.** Z_{Err} indicates a single-bit error (or odd number of multiple errors) in data flowing through the multiplexers or output latch. The output parity bit, ZP, is compared with the parity of the Z bus output generating a logic high on Z_{Err} if an error exists.
Z_{Err} can be tested with the test error input, T_{Err}, when an arithmetic operation is performed. When enabled, a logic high on T_{Err} will result in an incorrect parity of the arithmetic operation output Sum. This will be detected by the Z bus error logic as shown in the block diagram.

- Parity Output.** ZP is used to output the parity of the Z bus. It is generated independently of the Z bus, which adds another level of system error check.

ZP is the Exclusive-OR of the selected function before multiplexing onto the Z bus. For example, if the ALU were performing an AND operation, ZP would be:

$$ZP = XY7 \oplus XY6 \oplus XY5 \oplus \dots \oplus XY0$$

- Group Propagate/Generate.** Group propagate, \overline{PG} , and group generate, \overline{GG} , are used as inputs to external look-ahead carry logic for carry in signals that can be obtained with faster ripple techniques. The propagate output goes low when the maximum value occurs on the ALU outputs (255). Group generate occurs with a value of 256 or greater. These signals are useful only with arithmetic operations.
- Test Diode.** A test diode, TD, is connected to Pin 67 for use in measuring junction temperature. Pin 66 is the diode anode; Pin 67 the diode cathode.

Select Line Operation

One-Bit Shift Select

Control inputs CD60, CD61, and CD62 are used to give the ECL 8-bit slice a 1-bit shift left or a 1-bit shift right. A logic L on CD62 results in a 1-bit shift left whereas a logic H results in a 1-bit shift right operation. When CD60 is held at a logic L or CD61 is held at a logic H, no shift operation is performed. Table 2 illustrates the 1-bit shift operation.

Table 2

Operation	CD60	CD61	CD62
No Shift	L	X	X
No Shift	X	H	X
1-Bit Shift Left	H	L	L
1-Bit Shift Right	H	L	H

Mux B Select

Control inputs CD60, CD61, and CD62 are used to select the data path to the ALU output latch. When CD61 is held at a logic H, Mux B is enabled. CD60 and CD62 select ALU functions pass X, pass Y, shift left four bits or shift right four bits. (See Table 3.)

Table 3

Function	ZP	CD61	CD60	CD62
Not Enabled	See Table 4	L	X	X
Pass X	XP	H	L	L
Pass Y	YP	H	L	H
Shift Left 4 Bits	SL4 PAR	H	H	L
Shift Right 4 Bits	SR4 PAR	H	H	H

$$SL4\ PAR = [SL4 \oplus SL5 \oplus SL6 \oplus SL7] \bar{\oplus}$$

$$[(X0 + Y0) \oplus (X1 + Y1) \oplus (X2 + Y2) \oplus (X3 + Y3)]$$

$$SR4\ PAR = [SR0 \oplus SR1 \oplus SR2 \oplus SR3] \bar{\oplus}$$

$$[(X4 + Y4) \oplus (X5 + Y5) \oplus (X6 + Y6) \oplus (X7 + Y7)]$$

Mux A Select

Control inputs OPA, OPB, and CD61 are used to select the data path to the ALU output latch. When CD61 is held at a logic L, Mux A is enabled, OPA and OPB select ALU functions Sum, XOR, X + Y, or X • Y (see Figure 11). See Table 4.

Table 4

Function	ZP	CD61	OPA	OPB
Not Enabled	See Table 3	H	X	X
Sum	Sum PAR	L	L	L
XOR	XOR PAR	L	L	H
X • Y	AND PAR	L	H	L
X + Y	OR PAR	L	H	H

$$XOR\ PAR = (Shift\ PAR) \bar{\oplus} [XP \oplus YP]\ \text{where}$$

$$Shift\ PAR = [X7 \oplus X_{1N}] \bullet CD62 + (X8 \oplus X0) \bullet CD62 \bullet CD60 \bullet CD61$$

$$AND\ PAR = [(X0 \bullet Y0) \oplus (X1 \bullet Y1) \oplus (X2 \bullet Y2) \oplus (X3 \bullet Y3)] \bar{\oplus} [(X4 \bullet Y4) \oplus (X5 \bullet Y5) \oplus (X6 \bullet Y6) \oplus (X7 \bullet Y7)]$$

$$OR\ PAR = (AND\ PAR) \bar{\oplus} (XOR\ PAR)$$

$$Sum\ PAR = C_{1N} \oplus C1 \oplus C2 \oplus C3 \oplus C4 \oplus C5 \oplus C6 \oplus C7 \oplus T_{Err} \oplus (XOR\ PAR)$$

where C_{1N} is the carry-in for generating bit Z_l for $l = 1$ to 7.

Complement Y Select

Control input Comp inhibits or enables the complement operation. When Comp is at a logic L, Y data is passed. When Comp is at a logic H, Y is complemented.

Table 5

Operation	Comp
Pass Y	L
Complement Y	H

Table 6

Function	ZP	CD61	CD60	CD62	OPA	OPB	Comp
$X + Y + C_{1N}$	Sum PAR	L	L	X	L	L	L
$X + \bar{Y} \oplus C_{1N}$	Sum PAR	L	L	X	L	L	H
$X \oplus Y$	XOR PAR	L	L	X	L	H	L
$X \oplus \bar{Y}$	XOR PAR	L	L	X	L	H	H
$XSL + Y + C_{1N}$	Sum PAR	L	H	L	L	L	L
$XSL + \bar{Y} \oplus C_{1N}$	Sum PAR	L	H	L	L	L	H
$XSL \oplus Y$	XOR PAR	L	H	L	L	H	L
$XSL \oplus \bar{Y}$	XOR PAR	L	H	L	L	H	H
$XSR + Y + C_{1N}$	Sum PAR	L	H	H	L	L	L
$XSR + \bar{Y} \oplus C_{1N}$	Sum PAR	L	H	H	L	L	H
$XSR \oplus Y$	XOR PAR	L	H	H	L	H	L
$XSR \oplus \bar{Y}$	XOR PAR	L	H	H	L	H	H
$X \bullet Y$	AND PAR	L	X	X	H	L	X
$X + Y$	OR PAR	L	X	X	H	H	X
X	XP	L	L	L	X	X	X
Y	YP	H	L	H	X	X	X
Shift Left Four Bits ¹	SL4 PAR	H	H	L	X	X	X
Shift Right Four Bits ²	SR4 PAR	H	H	H	X	X	X

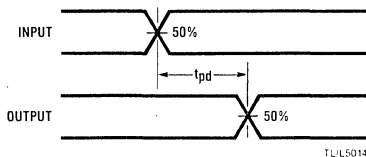
1. The least significant four bits of X or Y are shifted into the most significant four bits. The four least significant bits are replaced with SL7-SL4 inputs.

2. The most significant four bits of X or Y are shifted into the least significant four bits. The four most significant bits are replaced with SR3-SR0 inputs.

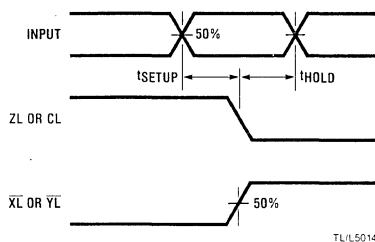
+ Logic Inclusive-OR. • Logical AND. ⊕ Logical Exclusive-OR.

Switching Waveforms

Propagation Delays



Setup and Hold



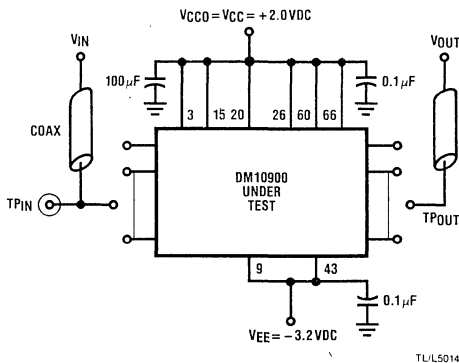
Setup and Hold

Test Procedure:

- Establish setup time with long t_{hold} .
- Keeping the leading edge of the input constant (t_{setup}), vary the trailing edge of the input to determine t_{hold} .

Switching Time Test Circuit

$$V_{CC0} = V_{CC} = +2.0 \text{ VDC}$$



50Ω termination to ground location in each scope channel input.

All input and output cables to the scope are equal lengths of 50Ω coaxial cable. Wire length should be < 1/4 inch from TPIN to output pin and TPOUT to output pin.

Setup and Hold Times (Nanoseconds) 0 to +70°C T_A (T_J not to exceed +115°C)

Input	Clock (Ref. Edge)	Output	Setup (Min.)	Hold (Min.)
X Bus, XP	$\overline{X}L$ (L→H)	All	1.6	+1
Y Bus, YP	$\overline{Y}L$ (L→H)	All	1.6	+1
X Bus, Y Bus, Comp.	ZL (H→L)	Z Bus	17.8	0
		ZP	19.2	0
XP, YP	ZL (H→L)	$\overline{C}N3, \overline{C}N7$	14.5	0
		ZP	11.7	0
$\overline{C}IN$	ZL (H→L)	Z Bus	12	-1
		ZP	14.3	-1
SL, SR	CL (HB→L)	$\overline{C}N3, \overline{C}N7$	8.6	-1
		Z Bus	6.1	+0.5
X8, XIN	ZL (H→L)	ZP	12	0
		Z Bus	15.5	-1
	CL (H→L)	ZP	17.2	-1
		$\overline{C}N3, \overline{C}N7$	12.1	-1
OPA, OPB	ZL (H→L)	Z Bus, ZP	10.6	+0.5
		Z Bus	24.2	+0.5
CD60, CD61, CD62	ZL (H→L)	ZP	26.1	0
		$\overline{C}N3, \overline{C}N7$	21.1	-1
	CL (H→L)	Z Bus	18.9	-0.5
$\overline{X}L, \overline{Y}L$ (H→L Edge)	ZL (H→L)	ZP	20.4	-1
		$\overline{C}N3, \overline{C}N7$	15.5	-1
T_{Err}	ZL (H→L)	ZP	7	0

Propagation Delay (Nanoseconds)

Input	Path		Output	0 to 70°C T _A (T _J not to exceed 115°)	
	Via	Mode		Typical	Maximum
X Bus	Adder	XOR	Z Bus	7.9	12.2
Y Bus	Adder	Arith.	Z Bus	11.6	17.8
Comp	Mux B	Logical	Z Bus	6.8	10.8
	Adder	Arith.	ZP	12.5	19.2
			C _{OUT}	7.5	11.5
			CN3, CN7	9.4	14.4
			ZD7, ZD3	13.9	20.7
			HSC	9.8	15.1
			Z _{Err}	16.7	25.7
			PG	7.5	11.5
			GG	7.4	11.3
XP			ZP	7.6	11.7
YP			HSC	6.8	10.4
			Z _{Err}	10.5	16.2
C _{IN}	Adder	Arith	Z Bus	7.8	12
			ZP	9.3	14.3
			C _{OUT}	2.8	4.3
			CN3, CN7	5.5	8.5
			ZD7, ZD3	10	15.3
			Z _{Err}	12.3	18.9
SL	MuxB	Shift 4 Bits	Z Bus	4	6.1
SR			ZP	7.8	12
			ZD7, ZD3	6.3	9.7
X8	Adder	Shift 1 Bit	Z Bus	10.1	15.5
X _{IN}			ZP	11.2	17.2
			C _{OUT}	6	9.2
			CN3, CN7	7.8	12
			ZD7, ZD3	12.3	18.9
			PG	6	9.2
			GG	5.8	8.9
			HSC	8.6	13.2
			Z _{Err}	15.5	23.8
T _{Err}		Z Parity Error Check	ZP	4.5	7
			Z _{Err}	7.5	11.5
X _L	Latch	Latch X, Y	Z Bus	12.3	18.9
Y _L			ZP	13.3	20.4
			C _{OUT}	8.3	12.7
			CN3, CN7	10	15.4
			ZD7, ZD3	14.5	22
			HSC	10.5	16.2
			Z _{Err}	17.4	26.8
			PG	8.2	12.6
			GG	8.1	12.4
OPA	Mux A	Select	Z Bus	6.9	10.6
OPB			ZP	5.9	9.1
			ZD7, ZD3	9.4	14.4
			Z _{Err}	11.4	17.5
CD60	Adder	Shift 1 Bit	Z Bus	15.7	24.2
CD61			ZP	17	26.1
CD62			C _{OUT}	11.6	17.9
			CN3, CN7	13.7	21
			ZD7, ZD3	18	27.7
			HSC	14.4	22.1
			Z _{Err}	21.3	32.7
			PG	12	18.5
			GG	11.9	18.3
ZL	Latch	Latch Z	Z Bus, ZP	3.3	5
			ZD7, ZD3	5.5	8.7
			Z _{Err}	7	11.6
CL	Latch	Arith	CN3, CN7	2.8	4.3

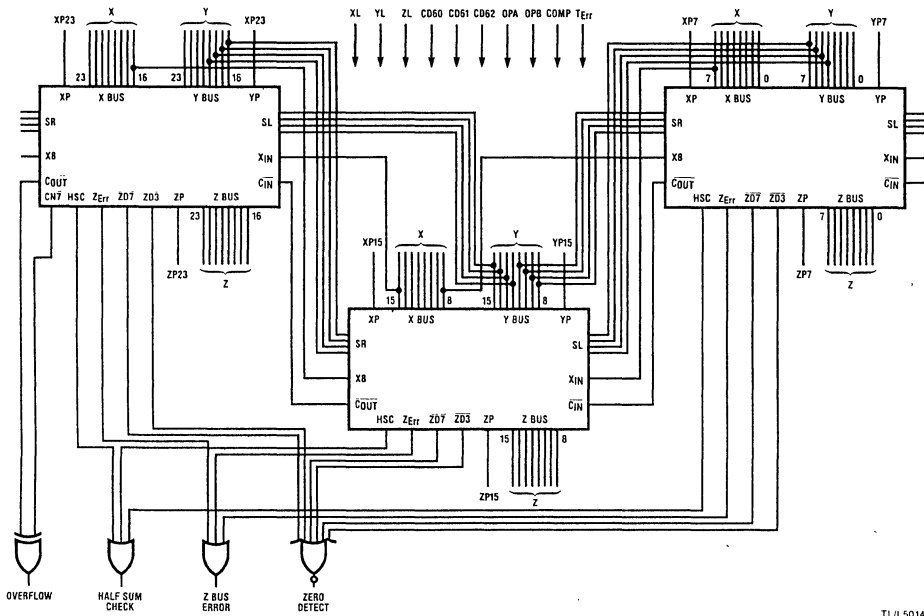


FIGURE 2. 24-Bit ALU Expansion Example

TL/L5014

Applications

IDM2900 Family Applications Information



SYSTEM ARCHITECTURE OF THE IDM2901A

The IDM2901 is designed for use in microprogrammed systems; figure 1 illustrates a typical configuration for such a system. All devices use a common clock while two registers provide control signals and data inputs to the CPU. One of the registers serves as a direct-data input to the device, whereas the other register provides a communications link between the 2901, the microprogram sequencer, and the microprogram storage device (RAM, ROM or PROM). The "memory store" device contains microinstruction sequences, typically 28 to 60 bits wide. When selected, these microinstructions control the IDM2901 and other circuits in order to execute the chosen operation. Address lines of the "store" device are driven by the microprogram sequencer. The sequencer can store an address, incre-

ment an address, jump to any address, and link subroutines. Control bits for the "next instruction" originate in the "microprogram store." This arrangement plus the fact that the control register is between the storage device and the 2901 means that the instruction can be accessed on one cycle and executed on the next cycle. In summary, as one instruction is executed, the next instruction is being read from microprogram memory. In such a configuration, system speed is improved because "access time" and "execution time" occur in parallel; without the "pipeline instruction register," these two operations would be implemented in serial order. Other speed-enhancement techniques are detailed later under "Speed Enhancement of Bipolar Bit-Slice Microprocessor Systems."

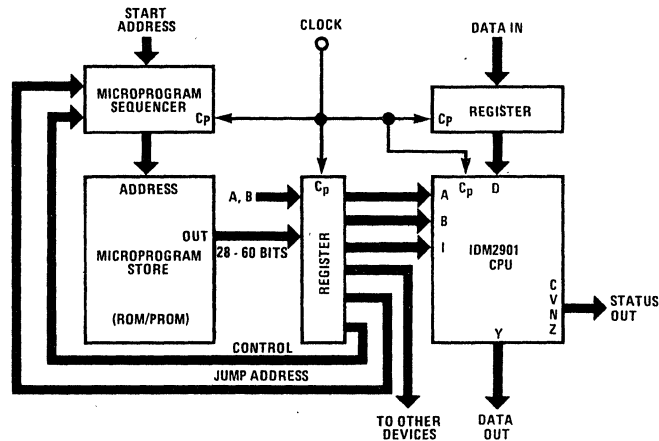


Figure 1. Microprogrammed System Using the IDM2901

EXPANDING THE IDM2901 BIT-SLICE MICROPROCESSOR

The IDM2901 is a 4-bit slice microprocessor; thus, any number of devices can be interconnected to produce, in 4-bit increments. CPUs of 8, 12, 16, 24, 36, or more bits. Figure 2 shows how three devices can be connected to form a 12-bit CPU using ripple carry; figure 3 shows a 16-bit CPU using carry look-ahead, and figure 4 shows the general carry look-ahead scheme for long words.

With exception of the carry interconnections, all expansion schemes are the same. The Q₃ and RAM₃ pins provide bidirectional left/right functions for the most

significant bit. Except for the last device in the string, the Q₃ and RAM₃ lines connect, respectively, to the Q₀ and RAM₀ lines of the next device. These connections permit the "Q" register of each device to be shifted left or right as a contiguous n-bit register; also, it allows output data from the ALU to be shifted left or right as a contiguous n-bit word prior to storage in RAM. As shown in the single-slice configuration (see figure 5), the shift lines at the LSB and MSB could be connected to the TRI-STATE multiplexer; the multiplexer can then be controlled by microcode to select appropriate shift-input signals.

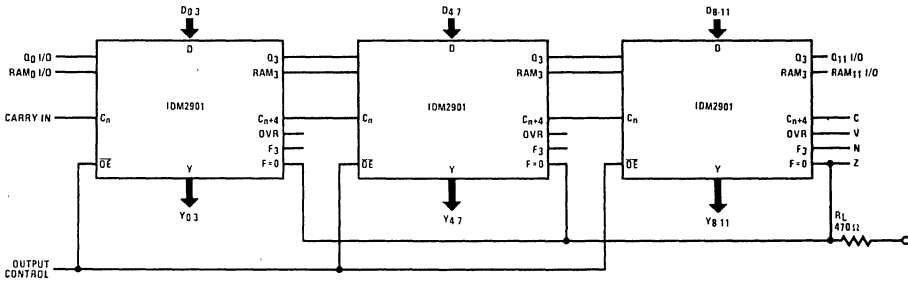


Figure 2. 12-Bit CPU with Ripple Carry

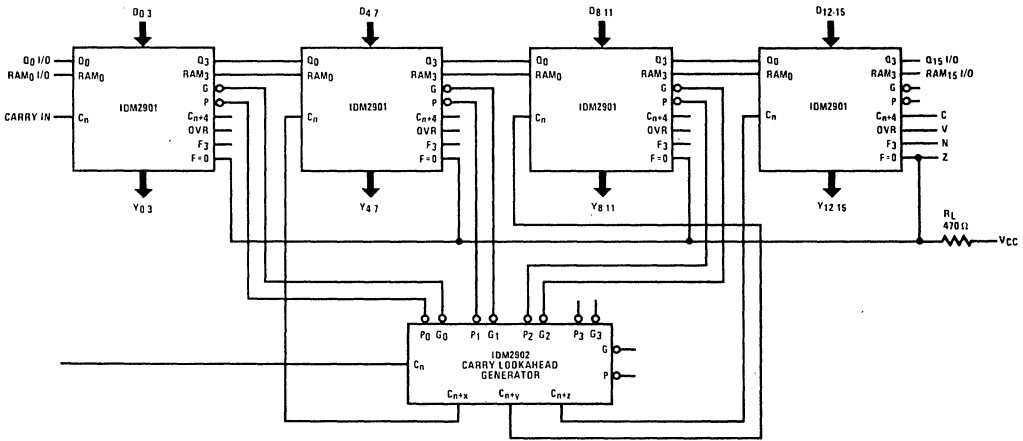


Figure 3. 16-Bit CPU Using Carry Lookahead

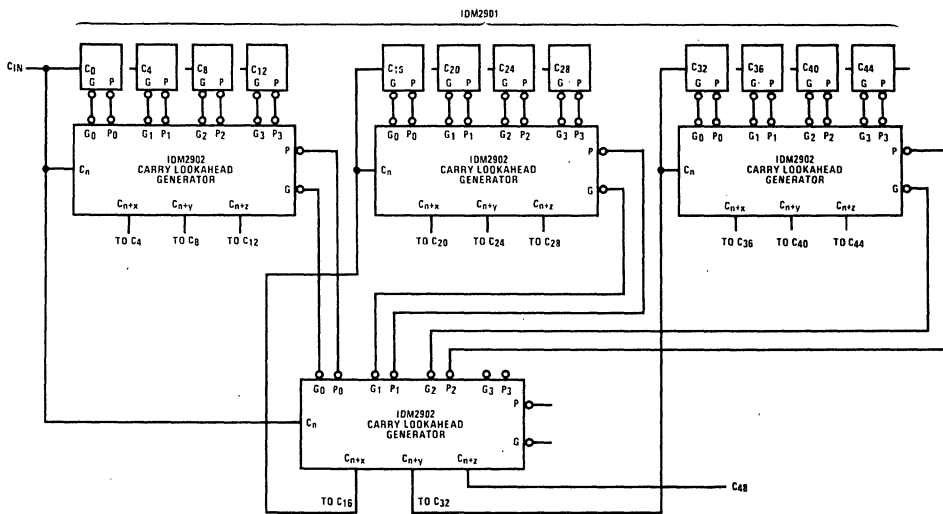


Figure 4. 48-Bit CPU Using Multiple Carry Lookahead

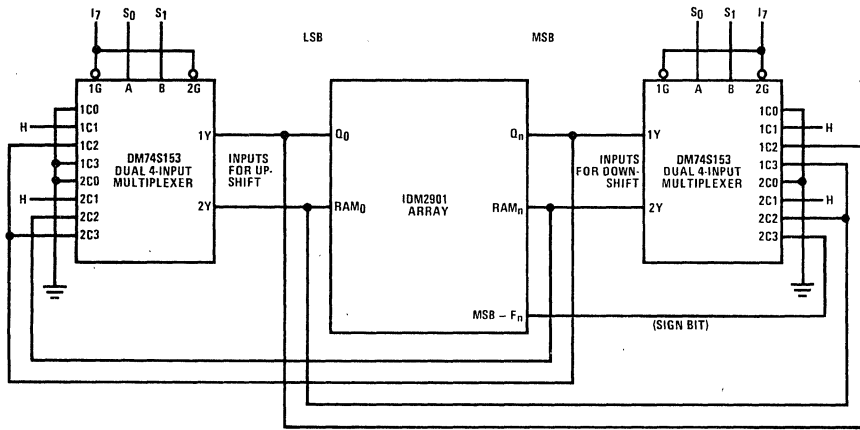


Figure 5. Typical Input/Output Shifting at End of Array

All "F=0" outputs are connected together through a pull-up resistor; this line is high only if the ALU contains all zeroes. Most systems use the "F=0" line as a "0" flag input to the processor status word. The overflow and F₃ pins are meaningful only when twos complement signed arithmetic is used. The overflow (V) output is high when the result of an arithmetic operation is a number requiring more bits than are available, causing the sign bit to be erroneous. The F₃ (MSB of ALU output) is the sign of the result in twos complement notation and indicates the negative (N) bit, of the processor status word. The carry (C) bit of the status word is taken from the most significant processor (D₁₂-D₁₅, figure 3) in the string; carry interconnections between devices can use either ripple carry or carry look-ahead. For ripple carry, the carry-out (C_{n+4}) of each device is connected to the carry-in (C_n) of the next most significant device; for example, C_{n+4} of device D₀-D₃ connects to C_n of D₄-D₇, C_{n+4} of D₄-D₇ connects to C_n of D₈-D₁₁, and so on for all interconnected devices.

As shown in figure 5, during shifting, TRI-STATE multiplexers are used to select new input information for the "Q" register and RAM; the left/right shift data is transferred between devices over bidirectional lines. Figure 5 shows how two dual 4-input multiplexers can be connected to provide four shift modes; in this case, I₇ (from the IDM2901A) is used to select the up-shift or down-

shift multiplexer. In this example, the four shift modes are defined below; these are followed by a table that provides an operating summary.

- Zero** On a down-shift, the MSB of RAM is set low (logic 0); if the Q register is also shifted, the MSB of this register is likewise set low. For an up-shift, the LSB of the affected register(s) is set low.
- One** Same as preceding description for "zero," except the MSB or LSB is set high (logic 1) rather than low (logic 0).
- Rotate** Single precision rotate – MSB of RAM shifts into LSB on a right shift; LSB shifts into MSB on a left shift. If shifted, the Q register bits are shifted in the same manner.
- Arithmetic** Double-length arithmetic shift provided the Q register is also shifted. On an up-shift, a "zero" is loaded into the LSB of the Q register and the MSB of the Q register is loaded into the LSB of RAM. On a down-shift, the LSB of RAM is loaded into the MSB of the Q register and the MSB (F_n = sign bit) of the ALU output is loaded into the MSB of RAM. (The same bit will also appear in the next least significant RAM bit.)

Code			Source of New Data				Shift	Type
I ₇	S ₁	S ₀	Q ₀	Q _n	RAM ₀	RAM _n		
H	L	L	0	Q _{n-1}	0	F _{n-1}	Up (Right)	Zero
H	L	H	1	Q _{n-1}	1	F _{n-1}		One
H	H	L	Q _n	Q _{n-1}	F _n	F _{n-1}		Rotate
H	H	H	0	Q _{n-1}	Q _n	F _{n-1}		Arithmetic
L	L	L	Q ₁	0	F ₁	0	Down (Left)	Zero
L	L	H	Q ₁	1	F ₁	1		One
L	H	L	Q ₁	Q ₀	F ₁	F ₀		Rotate
L	H	H	Q ₁	F ₀	F ₁	RAM _n = RAM _{n-1} = F _n		Arithmetic

Initial Register States

R	
0	Multiplier
1	Multiplicand
2	X
3	X

Final Register States

R	
0	Multiplier
1	Multiplicand
2	LSH Product
3	MSH Product

S, F →	D	Description	Repeat	Pin States (Octal)										Jump		
				A	B	I876	I543	I210	C _n	Q ₀	Q ₃	RAM ₀	RAM ₃	To	If	
O V A	Q	Move Multiplier to Q	—	0	X	0	3	4		X	X	X	X	X		
O B	B	Clear R ₃	—	X	3	2	4	3		X	X	X	X	X		
(O+B)/2 (A+B)/2	B	Cond. Add & Shift	n-1	1	3	4	0	1 or 3 I ₁ = Q ₀ L ₀	0	—	RAM ₀	—	F ₃ V OVR			
(B-O)/2 (B-A)/2	B	Cond. Subt. & Shift	—	1	3	4	1	1 or 3 I ₁ = Q ₀ L ₀	1	—	RAM ₀	—	F ₃ V OVR			
O V Q	B	Move LSH Prod. to R ₂	—	X	2	2	3	2		X	X	X	X	X		

X = Don't Care S = Source F = Function D = Destination

Figure 7. Twos Complement Multiplication

BYTE SWAPPING

Sometimes it is expedient or necessary to swap the two halves of a 16-bit word — interchange D₀₋₇ with D₈₋₁₅ and vice versa. A fast method of implementing the swap is to rotate the word in RAM, shifting 2 bits at a time — only four shift cycles are required. The same file register is selected at both A and B ports; these two values are added together with carry-in connected to carry-out, producing a single position shift to the right. The ALU is then shifted to the right one more position prior to storage in RAM. For example, the byte swap of R₀ would be implemented by repeating the following set of conditions four times:

$$A = B = 0; I = 701; RAM_0 = RAM_{15}; C_{1N} = C_{OUT}$$

INSTRUCTION FETCH CYCLE

Generally, execution of a microinstruction begins with an instruction fetch cycle. The address of the instruction to be fetched (and executed) is held in the program counter (PC) and, as the first step, this address must be put in the memory address register. Next, the PC is incremented to point to the next instruction. The instruction obtained from memory is loaded into the program sequencer, which causes a jump to the microcode that executes that particular instruction. The PC can be read out and incremented in one cycle by using destination code "2" and addressing the PC with both the A and B fields. The current value of PC will appear on the Y outputs and (PC+1) will be returned to the register. For example, if PC is in register 15:

$$A = B = 15; I = 203; \text{Carry-in} = 1$$

The PC contents will appear at the Y outputs via the A port of RAM. On the low-to-high transition of the clock pulse, the program counter will be incremented and the Y outputs will be loaded into the memory address register. During the next clock cycle, memory is read and, on the succeeding low-to-high transition of the

clock, the instruction is put into the instruction register of the program sequencer. Only two microcycles are required to complete the instruction fetch.

FILE EXPANSION

In certain applications, the sixteen registers contained within the IDM2901 are insufficient; thus, the number of registers must be expanded. The expansion is easily implemented via the IDM29903 addressable D register file. As shown in the IDM29903 data sheet, the device consists of sixteen 4-bit words; each word can be read asynchronously or written into on the next clock transition. Figure 8 shows the IDM2901 and the IDM29903 connected together to provide a file that is 32 words deep. As shown by the "file enable" logic and the "expansion interface" connections, it is easy to see how further expansion can be achieved. There are several possibilities which could be used for address decode of this 32-word file. The most versatile decoding system is simply to implement separate addresses for each file, that is, discrete A and B address fields for the IDM2901 and a separate address input for the IDM29903. As shown in the following sequence, extending the number of file registers allows round-robin shifting of information from one device to the other; thus, interfile data management is easily accomplished.

Assume the following file location:

- R₀ through R₁₅ are in IDM2901
- R₁₆ through R₃₁ are in IDM29903

Then:

1. R₀₋₁₅ + B₀₋₁₅ → B₀₋₁₅
2. R₀₋₁₅ + B₀₋₁₅ → B₁₆₋₃₁
3. R₁₆₋₃₁ + B₀₋₁₅ → B₀₋₁₅
4. R₁₆₋₃₁ + B₀₋₁₅ → B₁₆₋₃₁
5. R₁₆₋₃₁ + R₀₋₁₅ → Q

In the configuration shown in figure 8, single-cycle shifts do not work, except that R₀₋₁₅ can be right-shifted or left-shifted. Other shifts can be performed by making a transfer to the Q register, shifting, and then transferring back to the R₁₅₋₃₁ registers.

If system requirements prohibit the use of separate address decodes, common address decoding (figure 9) can be used; in this case, two 5-bit address fields are obtained via the IDM29751 and a 2-to-1 multiplexer is used to control the A/B address fields of the 2901.

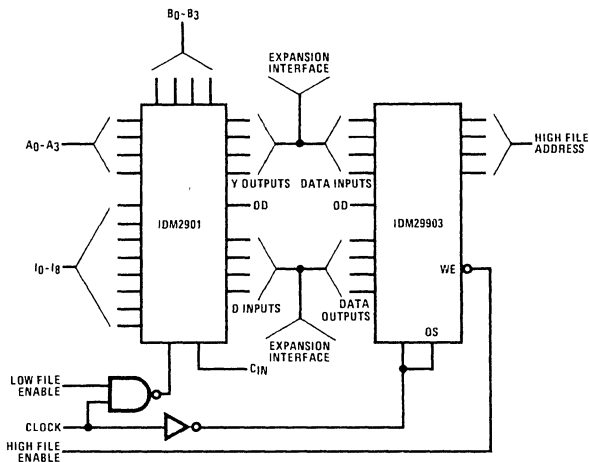


Figure 8. File Expansion Using Separate Address Fields for Each 16-Word File

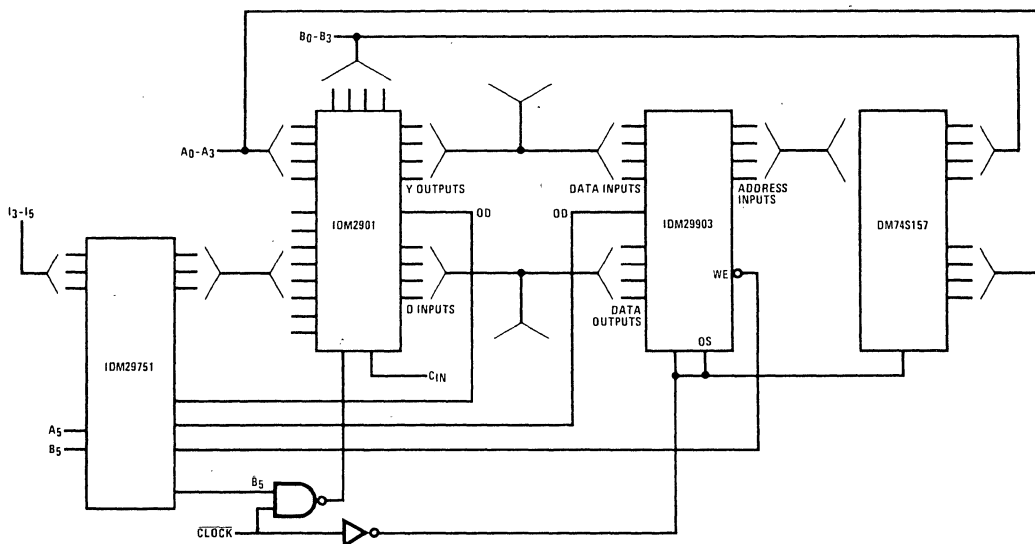


Figure 9. File Expansion Using Common Address Decoding

USING THE IDM2909A/11A IN A
COMPUTER CONTROL UNIT

Introduction

In any digital computing system, the Micro Control Unit (MCU) is almost always the most complicated subsystem. The MCU controls and supervises all bus activity, synchronizes internal and external events, and grants or denies access to peripherals and other external systems. Because of these many and varied duties, the MCU is complicated in concept, design, and implementation. The IDM2909A/11A Microprogram Sequencer provides an excellent tool for overall simplification of these parameters.

Computer Architecture

Typically, the architecture of most modern-day computers is as shown in figure 10. A common data bus is used; instructions, address operands, data, and other information is sent over this bus under the direction of a microprogram. The series of instructions within each microprogram selects the source of data and also the destination. Although only one data bus is shown in figure 10, a complicated system may contain several busses — each under control of the MCU.

The address bus in figure 10 is used to select a memory word for some internal function, or to select an input/output port for an external subsystem or peripheral. Data sources for the address bus can be the program counter, the memory address register, a direct memory address controller, an interface controller, or other; these functions are also under control of a microprogram command.

The arithmetic/logic unit (ALU) is that part of the processor that does the computational work. With a complex ALU, a large number of arithmetic and logical functions can be performed. As a minimum, the ALU must perform the arithmetic functions "A+B," "A-B," and "B-A"; usually, these functions can be performed in both fixed point and twos complement binary form. The minimum logical functions performed by the ALU are: "A OR B," "A AND B," and "A EXCLUSIVE-OR B." The arithmetic and logical functions are both implemented by the same circuit configurations — the difference being in gating. Besides the arithmetic and

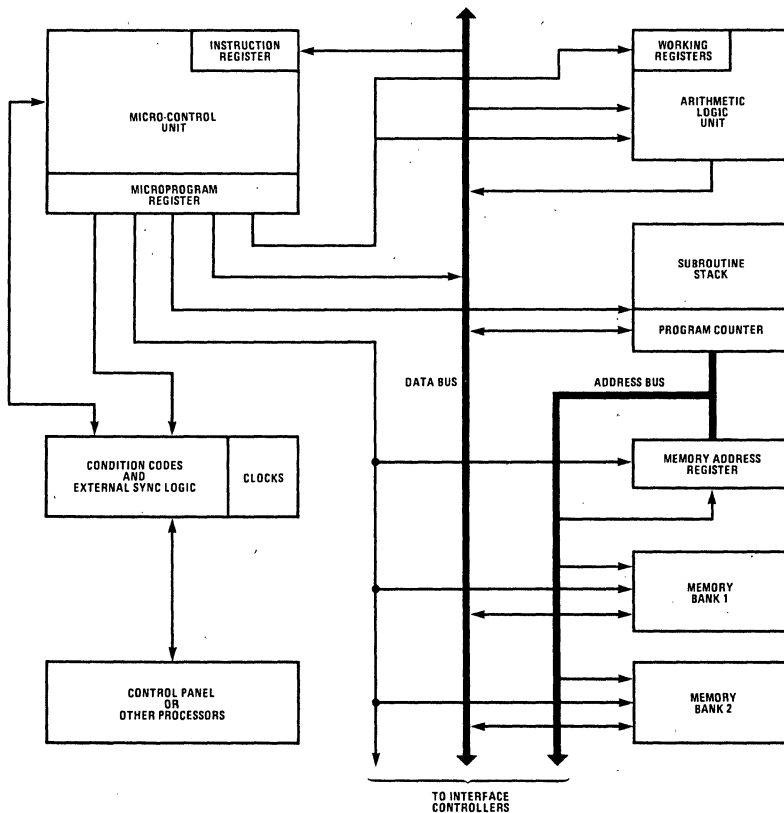


Figure 10. Generalized Computer Architecture

logic capabilities of the ALU, shift and rotate functions are also implemented as part of the basic instruction set. When an arithmetic or logical operation is performed by the ALU, a set of condition codes result. These condition codes include such variables as carry out, $A = B$, the sign bit, result equals zero, and so on. Along with other status information, these condition codes are stored in a register for later use by the programmer or micro control unit.

Third-generation processors also provide for a general-purpose register set that is available to the programmer to be used to hold variables that are used often — passing arguments to subroutines, referencing memory indirectly, and so on. Depending on the architecture of the machine, the general-purpose registers may be selected directly from the operands in the instruction register, from an address in the microprogram store, or one of the two sources as determined by a bit in the microprogram store.

The program counter and the memory address register are the two main sources of input to the address bus. The program counter contains the address of the next instruction or instruction operand that is to be fetched from main memory, and the memory address register contains instruction address operands that are necessary to fetch the data required for the execution of the current instruction. When exiting a subroutine, a subroutine address stack is provided to allow for easy handling of the return address linkage. The address stack is a last-in/first-out stack that is controlled by a jump-to-subroutine, PUSH, or a return-from-subroutine, POP, instruction from the MCU microprogram word.

In micro- and mini-computer systems, main memory consists of RAMs, ROMs, or more generally a combination of both. Typically, random access memories (RAMs) are slower than the micro control unit and the arithmetic logic unit. On the other hand, read only memories (ROMs) may be much faster than circuits within the MCU. Peripheral devices and multiprocessing systems present the same type of speed-interface problems; also, the MCU must contend with synchronizing events that occur asynchronously.

Control Sequence

The MCU contains an instruction register, micro-program storage, and usually a microprogram register. The initialization, fetch, and execute phases for a typical micro control unit are shown in figure 11. Regardless of system size and complexity, an initialization sequence is required to put control and storage elements in a known state such that control functions can be implemented in an orderly manner. For example, registers, condition codes, flags, and carry/link flip-flops are preset to a logic 1 or cleared to a logic 0. Likewise, it is sometimes necessary to initialize stack registers and/or main memory. The initialization process must be closely supervised to prevent alteration or damage to peripheral interfaces; furthermore, clock pulses must be withheld from the system until the initialization process is complete.

Usually, the initialization phase (1, figure 11) is started in one of three ways: (1) application of system power, (2) a "master reset" that is programmed or implemented by the operator, and (3) a detected error that cannot be corrected by the program. In a power-up generated initialization sequence, care must be given to the circuits

that detect the event and generate the timed reset signal; the operating sequence should not start until the entire power system is stable. Furthermore, since some equipment and components may be damaged if they require multiple voltages that are not applied in the proper order, the MCU is often used to sequence the enabling of power supplies.

In state 2 of figure 11, an instruction is fetched from the specified memory location and loaded into the instruction register. During state 3, the program counter is incremented and the previously fetched instruction is decoded. If another operand is required for the current instruction, state 3 is repeated and the various operands are loaded into the appropriate register. This process continues until the requirements of the instruction have been met.

In state 4, the macroinstruction is executed. As in all of the other states, the instruction execution state may require one or more microinstruction cycles. After completing state 4, the MCU returns to the fetch phase and continues to fetch-and-execute the programmed microcode.

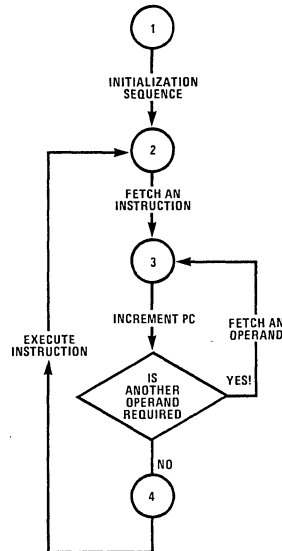


Figure 11. Initialization, Fetch, & Execute Phases for a Typical Microcomputer

Architecture of the Micro Control Unit

Basic components of the MCU are functionally shown in figure 12. The instruction register receives the instruction from main memory via the data bus; to minimize system overhead, the registers, main memory, and data bus are all of the same width. An instruction is broken down into two or more fields: the "Op Code" and one or more operands. The Op Code (Operation Code) is the instruction, whereas the operands are data used by the micro control unit in the execution of the instruction. For example, an operand might be the number of a selected register, a variable to be compared to the

accumulator, the address of an input/output port, and so on. Because the operand may be used as data, it must be presented to the data bus via an open-collector or TRI-STATE device; the Op Code and its subfields must also be distributed to the ALU and various other registers.

Usually, a macroinstruction contains more than one microinstruction; also, different classes of macroinstructions almost always require a different number of microprogram steps. In figure 12, some hardware can be eliminated by using the Op Code as the starting address of the microprogram ROM. This technique is not recommended simply because it is wasteful and inflexible; also, the entire system is affected by changes in the instruction set or the microprogram. To avoid these problems, a mapping ROM can be used.

To allow a greater range of starting addresses for the microprogram ROM, the output of the mapping ROM could be wider than the Op Code field that is used as the address input. Because ROM/PROM field widths are typically 4 bits or 8 bits wide, a reasonable choice for an 8-bit Op Code is a mapping ROM that is 12 bits wide. The starting address, as specified by the mapping ROM, is loaded into the microprogram counter which points to the first microinstruction in the microprogram ROM. When the output of the microprogram ROM stabilizes, it is loaded into the microprogram register.

The use of the microprogram register in this manner is called pipelining. The pipeline technique improves the overall machine speed by allowing the address of the

microprogram ROM to be changed and its output to settle while the current microinstruction is being executed. The microprogram sequence controller in figure 18 performs two basic functions: (1) synchronizes external events, and (2) uses the output of the test condition multiplexer to determine whether or not microprogram branches, jumps-to-subroutine, and returns-from-subroutine are to be made.

External signals of the microprogram sequence controller can be grouped into five categories: supervisory, condition codes, initialization, synchronization, and interrupts/clocks. The supervisory signals include "Run," "Halt," and "Pause." "Run" is a latched signal that enables the clock to the entire system. "Halt" disables the system clock and is only recognized during the instruction fetch microcycle; this is a latched signal. "Pause" is a level provided to the controller from an outside processor to temporarily suspend MCU control so that the external processor has uncontested access to resources of the computer.

Condition codes are stored in the program status word register and presented to the test condition multiplexer, where any of the codes may be selected by one of the microprogram fields in the microprogram register. If the condition code is true (logical 1), the output of the test condition multiplexer will enable a branch instruction in the microprogram. The condition codes are loaded into the program status word register after every ALU operation or interrupt request.

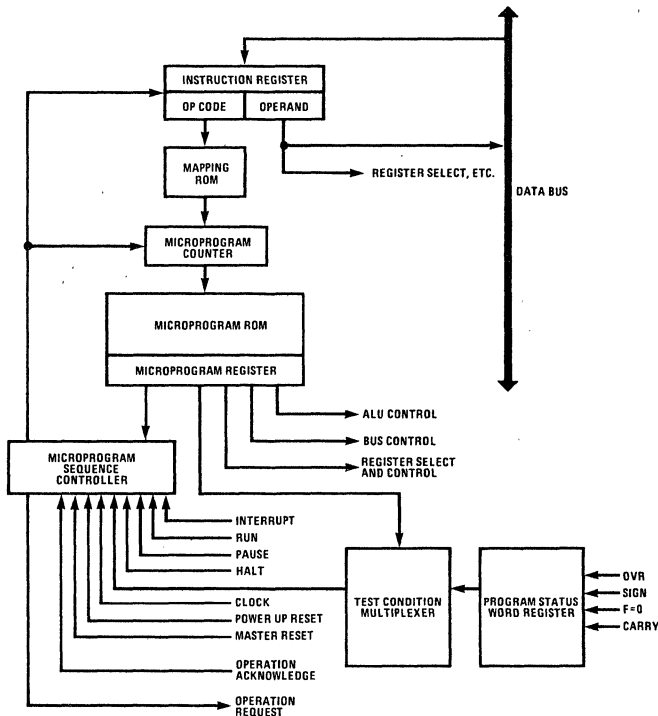


Figure 12. Basic Components of Micro Control Unit

Initialization lines include "Power-Up Reset" and "Master Reset" — these signals have been previously described. Synchronization lines include "Operation Request" and "Operation Acknowledge" — OPREQ and OPACK. These signals are used to synchronize external events whose speed is slower than that of the MCU. For example, when the MCU issues a memory reference instruction, an OPREQ signal is generated and, although the system clock continues to run, it is effectively disconnected from the micro control unit. Once the addressed memory has accessed the data and performed the read or write operation, it generates the OPACK signal; thus, the system clock is enabled to the MCU. When the memory or input/output cycle times are known and can be controlled, the MCU clock period can be adjusted to preclude the requirement for synchronizing signals.

An interrupt may occur at any time; however, it is normally recognized only during an instruction fetch. When the interrupt is recognized, the priority encoded interrupt vector is put into the program status word register and the microprogram ROM is updated with the address of the interrupt service routine. When the interrupt has been serviced, a return to the resident program is made via the previous program counter value.

MCU Instructions

There are two types of instructions recognized within the MCU — machine language or macroinstructions, and random logic replacement or microinstructions. Macroinstructions reside in main memory, are fetched and loaded into the instruction register, and then are decoded into microinstructions which directly control

resources of the computer. Two different types of macroinstructions are shown in figure 13. The register-to-register instruction consists of an 8-bit Op Code and two 4-bit operand fields; the branch-on instruction also consists of an 8-bit Op Code but the eight least significant bits define an 8-bit displacement address. In the register-to-register instruction, the operand defines the source and destination registers (A and B), that is, the result of an arithmetic/logic function using registers A and B will be stored in register B. In the branch-on instruction, the condition of the branch is implicit in the Op Code; the sum of the current program counter address and the displacement address will be stored in the program counter if the selected condition is logically true.

The word format for a typical microinstruction is shown in figure 13. The four least significant bits (B0-3) define the type of microinstruction (SEQUENCER FUNCTION) that is being executed. The second 4-bit field selects the "BRANCH CONDITION" (if the microinstruction is a branch instruction); two 1-bit fields may enable the interrupt and pause functions if the microinstruction is an instruction fetch command and disables the interrupts at all other times. The third microinstruction field is composed of two 3-bit subfields which are used to define the source and the destination of data (DATA BUS CONTROL). Depending upon the microinstruction function, the remaining 12-bit field is defined either as an arithmetic logic unit control field or as a microprogram branch address field (ALU & BRANCH ADDRESS BITS). There are various methods of mapping microinstruction control fields; however, for implementation of these fields in the examples that follow, the "ALU and Branch Address" is used.

Register-to-Register

15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Op Code								Reg. B				Reg. A			

Branch On Condition

15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
Op Code								Displacement							

ALU & Branch Address Bits								Data Bus Control				Synchronization Logic															
Function		Source		Destination		External Gating		Source		Destination		Pause	IEN	Branch Condition		Sequencer Function											
27	26	25	24	23	22	21	20	19	18	17	16	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0

Figure 13. Macro- and Micro-Instruction Fields

Implementing an MCU Using an IDM2909A

The IDM2909A address controller permits the designer to use the very latest in microprogramming techniques — microbranching, microsubroutines, and repetitive microinstruction execution. Instead of using sequential circuits which must be parallel loaded and sequentially incremented with separate clock pulses, the IDM2909A uses a combinational incrementer whose output is transferred to the microprogram counter on the rising edge of the clock pulse. As indicated in the data sheet (Part 1 of this manual), the primary function of the IDM2909A is to present an address to the microprogram ROM such that a microinstruction may be fetched and executed. The address information is available from any of four sources — an Address Register, a Microprogram Counter Register, a Direct or Branch Input, and a Subroutine Stack. The address source (figure 14) is chosen by using the one-of-four address multiplexer select lines, S₀ and S₁. The selected address can then be modified by the OR input lines or forced to zero before it is presented at the Y address output lines through a TRI-STATE buffer.

The OR input lines can be used in either of two ways. Selected OR inputs can be set to a logical 1; this will provide the logical OR of the selected address source and the OR input lines at the Y output — in this configuration the address can be “masked.” If a microprogram instruction of the SKIP or BRANCH classes is being executed and the microinstruction is aligned on an even address microprogram ROM word (the least significant address bit equals 0), then the least significant OR input

may be controlled by an external test condition multiplexer. If the result of the conditional test is logically false (logical 0), then the least significant bit can be modified to avoid the execution of the BRANCH or SKIP instruction. For such functions, all unused OR inputs must be tied to ground; similarly, if the 2, 3, 4, or n least significant bits of the selected address are 0, the associated OR input lines can be modified for an extended address range skip capability.

It is often desirable to get to a predefined state, or address. For instance, if the machine has just been turned on and it is necessary to perform an initialization sequence or a realtime event occurs where the processor control is required but the ongoing process information may not be destroyed, such as an interrupt, the OR inputs may be used. All of the OR inputs must be connected to the output of a positive logic gate so that when the event occurs the output of the gate goes to a logical 1, as do the Y output address lines. The ZERO input provides a similar capability, but it must normally be held at a logical 1 and only “pulled down” to 0 when the event occurs — causing all of the address output lines to go to 0.

For automatic testing of the memory and register system, the TRI-STATE output buffer that drives the Y lines can be used. That is, if the buffer output control (OE) is disabled, the Y lines are set to the high-impedance state which allows output lines of the automatic tester to be connected directly across the outputs.

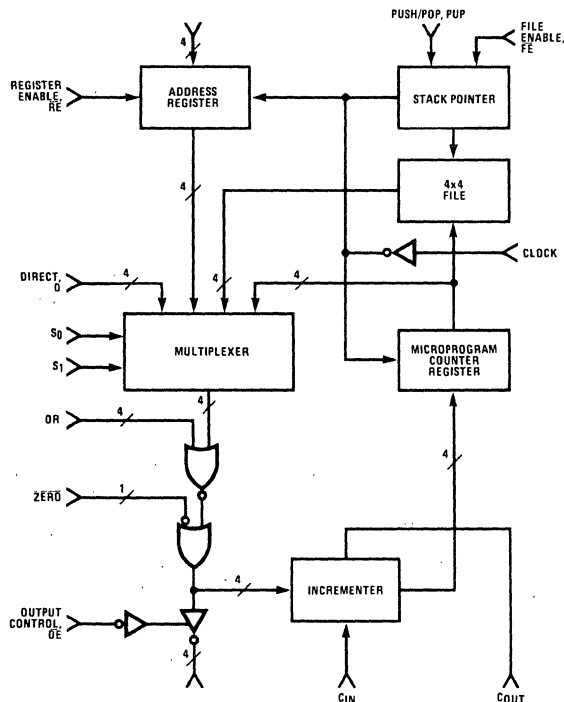


Figure 14. Functional Architecture of IDM2909A

The address register (as well as other storage devices of the IDM2909A) is parallel loaded from the R inputs when the register enable line (RE) is low on a positive-going clock transition. When entering the starting address of a microprogram, this is the ideal register to use because its contents are not only presented to the Y outputs, but also to the incrementer. The incrementer is an adder provided with an off-chip carry-in signal (C_n) and an off-chip carry-out signal (C_{OUT}); accordingly, several IDM2909A devices can be used in a cascade arrangement. The output from the incrementer is connected to a parallel load input on the microprogram counter register where it is loaded on the rising edge of the next clock pulse. If the microprogram counter is selected as the source address by subsequent microinstructions, it will be incremented by each succeeding clock pulse, thereby stepping through the microprogram.

As previously indicated, it is sometimes necessary (and often desirable) to provide a branch instruction and a branch address in a microprogram instruction. In such cases, data lines from the branch address field in the microinstruction can be feedback-connected to the data-direct (D) inputs of the IDM2909A; the source address

multiplexer can then select the branch input as the next microinstruction address. On the next clock pulse, the address is incremented and stored in the microprogram counter register.

The push/pop, or last-in/first-out (LIFO) stack, provides the microprogrammer with the same flexibility in subroutine execution that machine language programmers have. A 4-by-4 file whose address is controlled by a 2-bit up/down counter allows 4-deep nesting of microsubroutines. A push/pop control signal (PUP) determines whether the function being performed is a jump-to-subroutine (PUSH) or a return-from-subroutine (POP). When the file enable control line (FE) is low, the push/pop command is executed on the rising edge of the next clock pulse. After the subroutine is completed, a return to the address immediately following the jump-to-subroutine instruction is accomplished by selecting the stack as the source address and simultaneously executing a POP command.

One method of implementing the hardware shown in figure 12 is a configuration such as that in figure 15. Two IDM29901 octal edge-triggered flip-flops with

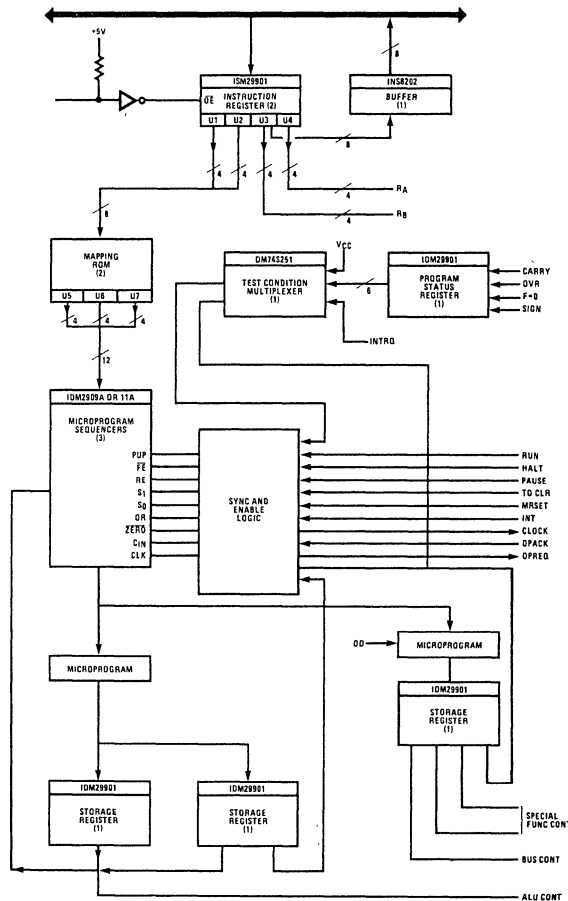


Figure 15. Using the IDM2909A to Implement a Computer Control Unit

TRI-STATE outputs (designated U_1 through U_4) make up the 16-bit instruction register. The most significant (U_1/U_2) registers contain the Op Code, whereas the least significant (U_3/U_4) registers contain the operand field. The TRI-STATE outputs from the Op Code register are connected to the address input of the mapping ROM. If, as shown, the output enable (OE) is held low by pulling up an inverter, troubleshooting and automatic testing of the system can be simplified because the tester has control of the memory system. The buffered output for the operand field is fed back to the eight least significant bits of the data bus for other register-modification purposes. In some applications, the Operand field for ALU functions will be used as two 4-bit subfields to specify a source register (R_A) and a source/destination register (R_B). In fact, this arrangement works extremely well if the IDM2901A microprocessor is used. The active TSL outputs are used for R_A and R_B data.

The two mapping ROMs are connected with common inputs but separate outputs. This memory configuration produces 256 words and a possible unique 16-bit address for each Op Code. There is considerable design flexibility and it is also easy to add additional instructions at a later time. The outputs of the mapping ROMs (or PROMs) connect to the register address inputs of the IDM2909A (or IDM2911A) microsequencers; in turn, the outputs of the sequencers specify address data for the microprogram ROMs. A recommended part type is shown for the region described as the microprogram storage. Since the 2909A or 2911A sequencer solution contains 12 addressing output bits, the size of this storage can grow to 4096 words before the microcontrol design must be modified. Almost any number of PROMs may be used for a system design since the application will dictate the number of words and the width of the word to be used in the microprogram.

As shown in figure 15, the microprogram register is split — one ROM (or PROM) providing special-function control, bus control, and ALU control, while the left

side provides next state control and the possible next state jump address or ALU control. In this configuration, the starting address from the mapping ROM is loaded into the internal register of the sequencer at some time before it is needed. Alternately, the direct inputs of the sequencer can be used; this method permits a single-cycle branch to the starting address.

The control bit fields for the ALU supervise all external gating and bit manipulation, whereas the other control fields provide source/destination bus control. Whenever the processor is running, the TRI-STATE output enable lines are held low, enabling the output.

If a "Pause" is implemented (a DMA function as an example), the outputs are disabled so that an external or peripheral processor can gain access to the control line.

Depending upon the application, the sync and enable logic can be relatively simple or it can be very complex. On the one hand, these circuits must satisfy the control requirements of the IDM2909A sequencer and the IDM2901, and on the other hand, they must provide the proper interface with externally-generated control signals. For the most part, internal control (within the MCU) is handled by decoding of the functions shown in figure 16.

The ability to execute the same microinstruction a number of times was mentioned earlier; technically, the value of this capability lies outside the micro control unit. For example, consider the macroinstruction format for a register-to-register instruction as shown in figure 19. If the Op Code is a Shift or Rotate instruction, it is desirable for the programmer to move the data word over a range of 1 to 16 bit positions with a single instruction rather than multiple execution of the same instruction. If the two operand subfields (R_A and R_B) are defined as R_A equals the number of bit positions the data is to be moved and R_B as the affected register, it is easy to see how this function can be implemented. (Additional hardware requirements are shown in figure 17.)

	Microprogram Sequencer Function					Function Description	Microprogram Sequencer Control							
							O7	O6	O5	O4	O3	O2	O1	O0
	A4	A3	A2	A1	A0		TEST ENABLE	OR	ZERO	CIN	RE	FE	S0, PUP	S1
Test Condition Disabled or False	0	0	0	0	0	Initialize System	L	X	L	H	H	H	X	X
	0	0	0	0	1	Branch Test	H	L	H	H	H	H	L	L
	0	0	0	1	0	Jump to Subroutine Test	H	L	H	H	H	H	L	L
	0	0	0	1	1	Return from Subroutine	H	L	H	H	H	H	L	L
	0	0	1	0	0	Execute Program	L	L	H	H	H	H	L	L
	0	0	1	0	1	External Carry Control	L	L	H	*	H	H	L	L
	0	0	1	1	0		L	L	H	H	H	H	L	L
	0	0	1	1	1		L	L	H	H	H	H	L	L
	0	1	0	0	0	This Group Undefined	L	L	H	H	H	H	L	L
	0	1	0	0	1		L	L	H	H	H	H	L	L
	0	1	0	1	0		L	L	H	H	H	H	L	L
	0	1	0	1	1		L	L	H	H	H	H	L	L
	0	1	1	0	0	Load Mapped (Starting) Address Fetch Instruction	L	L	H	H	H	H	L	L
	0	1	1	0	1		L	L	H	H	H	H	L	L
	0	1	1	1	0		L	L	H	H	L	H	H	L
	0	1	1	1	1		H	L	H	H	H	H	L	L
Test Condition Enabled and True	1	0	0	0	0	This State Undefined	L	-	-	-	-	-	-	-
	1	0	0	0	1	Execute Branch	H	L	H	H	H	H	H	H
	1	0	0	1	0	Execute Jump	H	L	H	H	H	L	H	H
	1	0	0	1	1	Execute Return	H	L	H	H	H	L	L	H
	1	0	1	0	0		L	-	-	-	-	-	-	-
	1	0	1	0	1		L	-	-	-	-	-	-	-
	1	0	1	1	0		L	-	-	-	-	-	-	-
	1	0	1	1	1		L	-	-	-	-	-	-	-
	1	1	0	0	0	This State Undefined	L	-	-	-	-	-	-	-
	1	1	0	0	1		L	-	-	-	-	-	-	-
	1	1	0	1	0		L	-	-	-	-	-	-	-
	1	1	0	1	1		L	-	-	-	-	-	-	-
	1	1	1	0	0	Service Interrupt or Pause	L	-	-	-	-	-	-	-
	1	1	1	0	1		L	-	-	-	-	-	-	-
	1	1	1	1	0		L	-	-	-	-	-	-	-
	1	1	1	1	1		H	H	H	H	H	H	X	X

*Value of this bit depends on logic implementation.

Figure 16. Function Table for IDM2909 (or IDM2911) Microprogram Sequencer

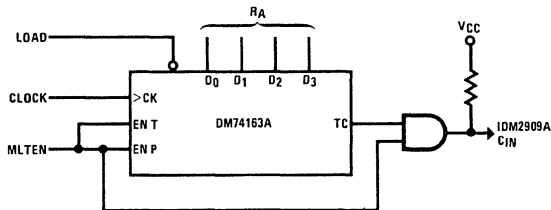


Figure 17. Example of Interactive Microinstruction Control

SPEED ENHANCEMENT OF BIPOLAR BIT-SLICE MICROPROCESSOR SYSTEMS

Review of Critical Timing Paths

In order to identify potential areas for speed improvement, it is helpful to review the critical timing paths in a typical bipolar microprocessor. First, consider the simple system organization shown in figure 18. In this system, the address register is clocked at the beginning of the microcycle. When the microinstruction is valid at the ROM output, two basic paths must be considered. One path consists of accessing data from the registers, propagation through the ALU, and storing the result in a data register and a status register. The other path involves the test condition multiplexer and sequence

controller. Typical timing for such a system is shown in figure 19. After the microinstruction is valid, the two paths are indicated by arrows. In a typical system design, the minimum microcycle period is limited by the delay path through the registers and ALU — shown as "ALU Results May Be Clocked" in figure 19.

If the path delays are such that the sequencer output is valid before the path through the registers and ALU has stabilized, a modification to the system shown in figure

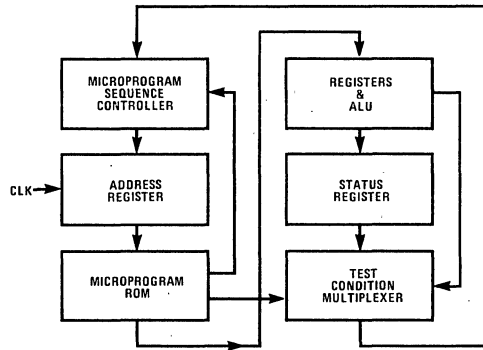


Figure 18. Simplified Block of Microprogrammed Processor

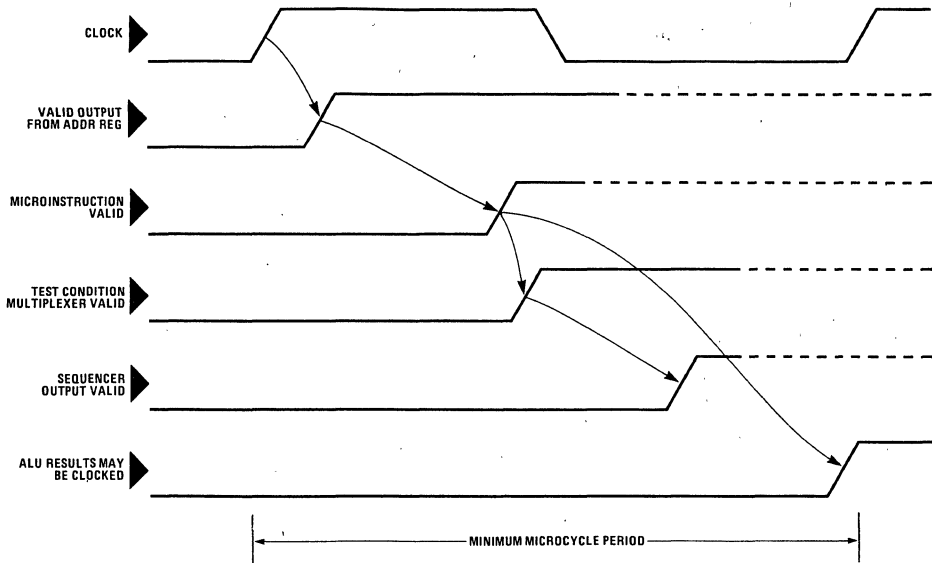


Figure 19. Typical Timing Diagram for Microprogrammed System Shown in figure 18

18 can provide improved performance. Such a modified system with typical timing is shown in figure 20 — this is frequently called a pipelined organization. The name results from the fact that while one microinstruction is being executed, another microinstruction is simultaneously being accessed. A register is added to the output of the ROM and the address register which was used to hold the output of the sequencer logic is not

used. The clock causes the next microinstruction to appear at the output of the microprogram register. The sequencer output is allowed to access the microprogram ROM to fetch the next microinstruction while the data is propagating through the registers and ALU. In this way, the access time of the ROM may be overlapped with the execution of the microinstruction by the registers and ALU.

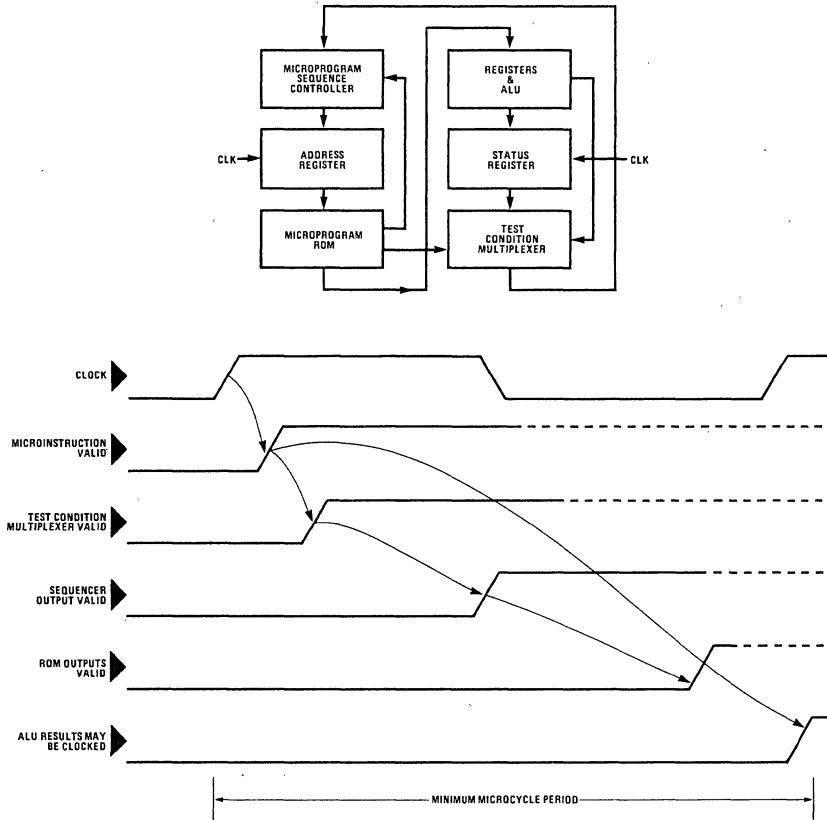


Figure 20. Pipelined Organization with Typical Timing

Predicting Test Condition Results for Higher Performance

In order for the pipelined organization of figure 20 to provide a performance advantage over the simple system shown in figure 18, the delay path through the sequencer and microprogram ROM must be faster than the path through the registers and ALU. In the timing diagram of figure 20, the sequencer output is valid early enough for the total access time of the ROM to be overlapped, that is, the ROM access time does not influence the required duration of the microcycle period. To satisfy this condition, the sequencer logic must be relatively high speed, and most importantly, the test condition multiplexer inputs must be valid at an early point in the microcycle. The latter requirement is quite unfortunate, since it implies that test conditions based upon the result of

ALU operations in the current microcycle may not be used. This forces the user to either provide more status register bits (the status register outputs contain the results of operations performed on earlier microcycles) and/or execute an additional microinstruction in order to perform an operation and test the result. Thus the consequences of not permitting test conditions based upon the result of the current ALU operation cost the user both additional hardware and execution time.

An effective solution to this problem is to design the system so that the sequencer logic is conditioned on the basis of a predicted value for the test condition multiplexer output, and the ROM is accessed on this assump-

tion. After the ALU result is stable and has propagated through the test condition multiplexer, the predicted value of the multiplexer output is compared with the actual value of its output. If the predicted value was correct, the next microinstruction in sequence (i.e., the one which was being accessed) is executed. On the other hand, if the predicted value of the test condition multiplexer is different from the actual value, the conditioning of the sequencer logic is modified correspondingly, and the time duration of the microcycle is extended in order to allow time for the modification to propagate through the sequence controller logic and access the ROM. Since the microprogrammer can frequently predict the results of test conditions with a frequency of success that is much better than 50%, a relatively small fraction of the microcycles must be extended. Two examples that illustrate where the programmer can, with a high degree of success, predict results of a test condition are:

- Testing for a stack overflow condition. The stack pointer (contained in an internal register) is compared with a boundary value (contained in another register). It is of course extremely infrequent that the result of this test indicates an overflow condition in normal circumstances.
- Test of a loop counter. In a microprogrammed multiply or divide algorithm, a loop counter must be tested on each pass through the loop. For a 16-bit machine, the test would typically be performed 16 times but the result could be accurately predicted 15/16 of the time.

Variable Microcycle Period

As was discussed earlier, the delay through the registers and ALU is typically the path which limits system performance. The magnitude of this delay can vary considerably depending upon which micro-operation is being performed. Table 1 lists a variety of operations together with the microcycle period requirements for a pipelined system which was designed to use the recently announced IDM2901. Note that the longest operation requires about 75% more execution time than the shortest operation (this percentage difference is even greater for a system using the first generation version of the 2901).

Table 1. Microcycle Period Requirements for Various Operations Using a Pipelined System

Operation Performed	Microcycle Time (ns)
Logic operation; status register not modified; no test of result	98
Arithmetic operation; status register not modified; no test of result	133
Add and shift; status register not modified; no test of result	172
Multiply cycle; Q ₀ used to determine I ₁ of 2901	172
Arithmetic operation; status register modified; no test of result	169
Arithmetic operation; status register not modified; result used as test condition (no extend caused by incorrect prediction)	165

The most straightforward design approach is to simply calculate the worst case time period, and design the clock generator circuit to provide that time for all operations. It is evident that a speed improvement would be obtained if the clock generator could be programmed to modify the microcycle period in accordance with the requirements of the operation which is to be performed. If the operations which establish the worst case time period are performed relatively infrequently, then the system performance improvement which can be achieved by programming the microcycle period is greater than might first be imagined.

Examples of Performance with Various System Configurations

In order to illustrate the performance which results from the various system organizations described above, it is helpful to present numerical values which were obtained from a design study. Five system organizations were considered. The systems were evaluated based upon the time required to execute a variety of instructions typical of those used by a minicomputer. These results are useful for gaining an insight into the performance which may be obtained for a particular type of system organization. Obviously, the results of these studies are dependent upon component specifications — ROMs, registers, gates, and LSI devices. Thus, when choosing an organization for a new system design, the designer should perform a similar analysis using specifications of available components in order to make realistic decisions of cost versus performance.

System 1: This system was equivalent to that shown in figure 18. It was a non-pipelined organization and test conditions were based upon results of operations performed on the previous microcycle. A fixed microcycle period of 225 nanoseconds was used; this period was necessitated by the multiply instruction.

System 2: This evaluation was based on a "pipelined" system organization similar to that shown in figure 20. Test conditions were based upon results of previous microcycles and a fixed microcycle time of 172 nanoseconds was used. The pipelined organization allows the microcycle period to be reduced by 48 nanoseconds less than the cycle time for System 1.

System 3: This system was the same as System 2 except that test conditions based upon results of the current microcycle were used and the technique of predicting test condition results was utilized. The microcycle period was fixed at 172 nanoseconds. The time necessary for the result of the current operation to propagate through the test condition multiplexer and determine whether an extended cycle was needed did not require a longer period than the 172 nanoseconds established by the operation needed by the multiply instruction. An extended cycle adds 86 nanoseconds (one half microcycle) to the normal microcycle period.

System 4: This system was the same as System 2 except that a variable microcycle period was used. Test conditions were based upon the results from the current microcycle; however, no prediction of test conditions with an extended cycle for incorrect prediction was performed. Instead, those microinstructions which required more time to allow for propagation of the result through the test condition multiplexer and sequence controller were simply programmed to be of

longer duration. Microcycle periods of either 103, 137, 172, or 206 nanoseconds could be used depending upon the needs of each microinstruction. A conditional branch based upon the result of an arithmetic operation requires 235 nanoseconds with this system organization. This time exceeds the period of the longest available microcycle (206 nanoseconds). However, the conditional branch may be executed with adequate time margin by repeating the arithmetic operation on two successive microcycles: one of 130 nanoseconds followed by one of 137 nanoseconds — a total of 240 nanoseconds. Although this approach of repeating the arithmetic operation may require more microcode locations, it does offer even greater flexibility in tailoring the microcycle period to the needs of the operation being performed.

System 5: This system combines the techniques used in Systems 3 and 4. Variable length microcycles (103, 137, 172, or 206 nanoseconds) could be used. The technique of predicting test condition results was used and, when the cycle was extended due to an incorrect prediction, an additional 86 nanoseconds were added.

Table 2 shows the instructions typically used in a mini-computer that is configured in one of the foregoing system organizations. The execution times specified in table 2 for each instruction type were derived by using the execution time of System 1 as a baseline reference. The relative execution speed for each of the five systems can best be appreciated by examining the data given in table 3.

The instructions (described below) were chosen for a variety of reasons:

1. LD, JMP, and ST (Load, Jump, and Store) were chosen because they are among the most frequently used instructions, and thus are ones for which execution time optimization is quite important. Since these instructions do not involve test conditions based upon results of ALU operations, note that the technique of prediction does not improve the execution time.
2. JSR and BOC (Jump to Subroutine and Branch on Condition) are frequently used instructions. They were chosen in order to illustrate the advantages of prediction of test condition results. For JSR, it was assumed that the test condition result was always predicted correctly (i.e., no stack out of bounds occurs). For BOC, it was assumed that the test condition result was predicted correctly 50% of the time. The two values given for BOC correspond to the cases where: (a) there is no branch and (b) the branch occurs.
3. ADD and MOVE were chosen primarily because they are used by some as a figure-of-merit for machine performance. The figure shown for MOVE is the time needed for each pass through the loop which reads data from one location in memory and stores it in a second location. The advantage of the technique of prediction of current test conditions from previous microcycles does not show up in the figures shown by JSR and MOVE. This is because it was possible to

Table 2. Instruction Execution Time (ns) with Various System Organizations

System Organization	Instruction Type				
	LD, JMP, & ST	JSR	BOC	ADD	Loop for MOVE
System 1 — non-pipelined; test condition from previous μ cycle	920	1610	920 or 1150	920	920N
System 2 — pipelined; no prediction; test condition from previous μ cycle	688	1204	688 or 860	688	688N
System 3 — pipelined with prediction; test condition from current μ cycle	688	1204	559 or 731	688	688N
System 4 — pipelined; no prediction; variable length μ cycle; test condition from current μ cycle	480	960	482 or 619	549	617
System 5 — pipelined with prediction and variable μ cycle length	480	892	412 or 549	549	549N

Note: The reason JSR & Loop for MOVE don't improve with System 3 is that a way was found to write a code without an extra cycle.

Table 3. Relative Instruction Execution Rate with Various System Organizations (Execution speed as a speed improvement factor of System 1)

System Organization	Instruction Type				
	LD, JMP, & ST	JSR	BOC	ADD	Loop for MOVE
System 1 — non-pipelined; test condition from previous μ cycle	1.0	1.0	1.0 or 1.0	1.0	1.0
System 2 — pipelined; no prediction; test condition from previous μ cycle	1.34	1.34	1.34 or 1.34	1.34	1.34
System 3 — pipelined with prediction; test condition from current μ cycle	1.34	1.34	1.64 or 1.57	1.34	1.34
System 4 — pipelined; no prediction; variable length μ cycle; test condition from current μ cycle	1.91	1.67	1.91 or 1.85	1.67	1.49
System 5 — pipelined with prediction and variable μ cycle length	1.91	1.80	2.23 or 2.09	1.67	1.67

write the microprogram with the same number of microinstructions for both systems. This was not the case with BOC, where an additional microinstruction was needed in order to conform to the requirement that test conditions be based upon results of the previous microcycle with System 1 and System 2.

Conclusions

Execution time calculations were made for a system where the macro-level instructions and data are stored in a (main) memory with very fast access time. Thus, it is assumed that it is not necessary to extend the clock cycle when reading from main memory. Although this is frequently not a valid assumption, it was necessary in order to simplify the presentation of results. If the memory access time is significant (say, greater than 200 nanoseconds), the relative improvement which can be obtained with the system organizations described here is somewhat less impressive. This is because the main memory access time may be overlapped to a greater extent with the system organizations having longer microcycle times. The overlapping is particularly important for those instructions which make multiple memory references, that is, LD and ST instructions require two memory reads, whereas the JMP instruction requires only one memory read. Conclusions may be drawn based upon a study of the results presented in table 3. Observe that the technique of using a variable microcycle period provides an impressive improvement in performance. Of course, this is a direct result of the fairly wide range of time intervals required for the various micro-operations presented in table 1. When the micro-operations which are performed most frequently can use the short execution cycle, the performance

gained from the variable microcycle period has the most impact on overall throughput of the machine. When designing a machine with variable microcycle periods, the clever designer will concentrate his efforts toward speed optimization for the most frequently performed micro-operations. It may be possible to save hardware costs by allowing the microcycle time required for the infrequently performed operations to be longer. Thus, the variable-length microcycle approach to design offers design freedom which can possibly reduce costs as well as improve performance.

Timing Generator Design Example

A timing generator which has been designed to meet the general objectives discussed in the preceding paragraphs is shown in figure 21. This circuit generates one of two clock intervals (oscillator period $\times 4$ or $\times 6$) under microprogram control. A variation of this basic idea but providing a choice of four clock periods (4, 5, 6, or 7 times the basic oscillator period) is shown in figure 22. The circuit also provides for comparing the output of the test condition multiplexer with a predicted value (from the microprogram ROM). If the actual test multiplexer output does not match the predicted value, the clock period is extended (by 3 oscillator periods) and an alternate set of inputs to the sequencer logic is provided.

The key element of the circuit is a 74S195 shift register. Use of Schottky circuits allows operation at an oscillator frequency up to 33 MHz. This permits the generation of a microcycle period of 120 ns with programmable increments of 30 ns (for the clock generator which provides four programmable clock intervals, this would allow clock periods of 120, 150, 180, and 210 nanoseconds).

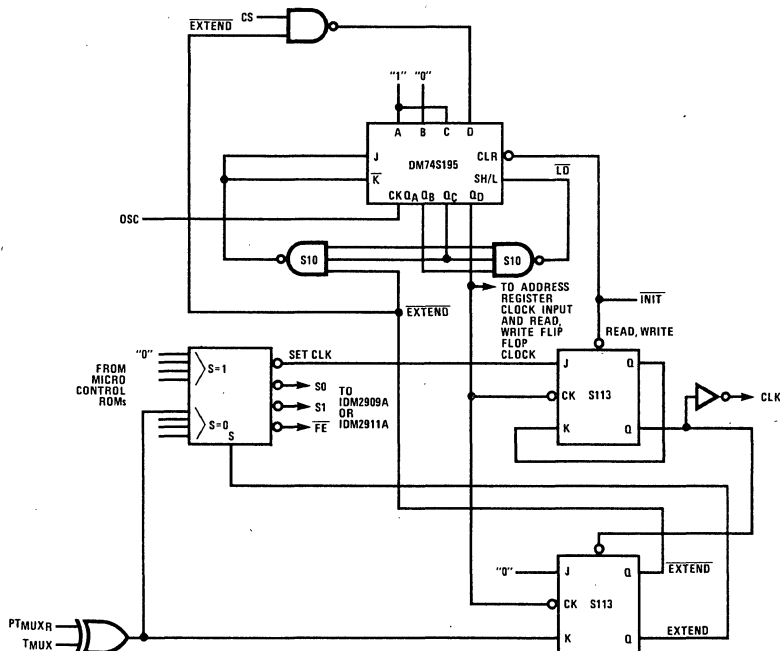


Figure 21. Two-Interval Programmable Timing Generator

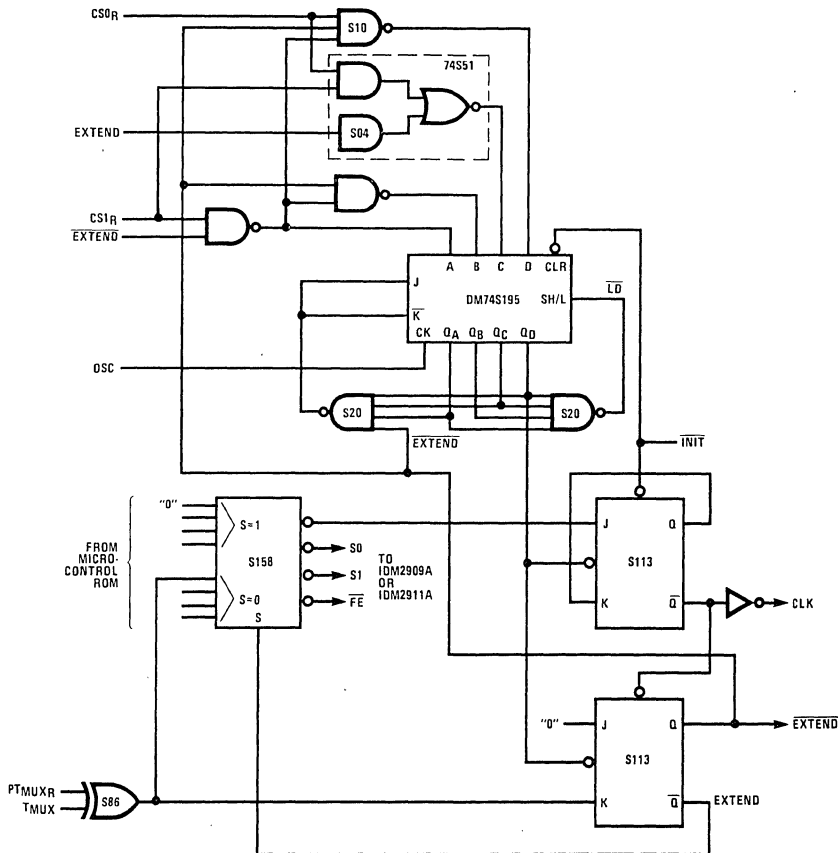


Figure 22. Four-Interval Programmable Timing Generator

The operation of the timing generator is best understood by reference to the state diagram shown in figure 23. Transitions from one state to another are made on each rising edge of OSC. The state of the shift register ($Q_A Q_B Q_C Q_D$) along with the state of CLK (the system clock) is specified in the state diagram. Assume that the clock (CLK) has just made a 0-to-1 transition indicating the start of a new microcycle (1110, CLK=1). EXTEND is a logic 0. The new outputs of the microprogram register then become valid resulting in the new values for Cycle Select (CS). (CS is a 1-bit value for the 2-interval circuit and a 2-bit value for the 4-interval circuit.) Cycle Select (CS) determines the state transition after CLK has been high for almost two OSC periods and thereby programs the duration of CLK. This is achieved by parallel loading the shift register with the desired value. State transitions then occur as determined by shifting the DM74S195. The clock input to the flip-flop which generates CLK is provided by the Q_D output of the DM74S195. CLK goes low when the DM74S195

reaches the 1010 state. On the next negative-going transition of Q_D , after CLK has been low for almost two OSC periods, the SETCLK output of the DM74S158 2:1 multiplexer determines whether CLK is set (the case when TMUX, the output of the test condition multiplexer is the same as PTMUX, the predicted value of TMUX) or CLK remains reset (corresponding to the case where TMUX is different from PTMUX). If CLK is set at this time, the sequence which was described above repeats in the same fashion. On the other hand, if TMUX was not predicted correctly, CLK will remain reset, and EXTEND will go to a logic 1. This causes the DM74S158 multiplexer to select the alternate set of inputs to the micro-sequencer logic (S_0 , S_1 , and FE) and causes SET CLK to go to a logic 1. After EXTEND has been active for three OSC periods (thus providing time to allow for propagation through the sequencer logic and microprogram ROM access), Q_D will make another negative-going transition, and CLK will be set, which in turn causes EXTEND to return to its logic 0 condition.

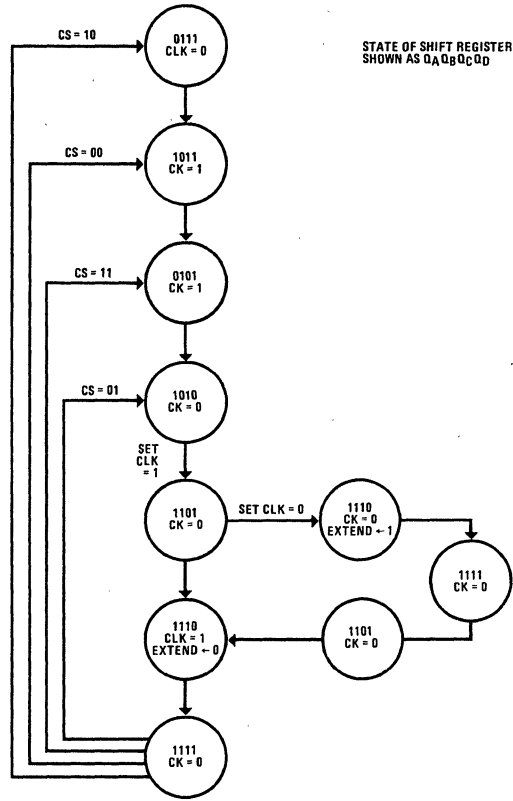


Figure 23. State Diagram for Four-Interval Programmable Timing Generator

Bit-Slice Microprocessor Design Takes a Giant Step Forward with "Schottky-Coupled-Logic" Circuits

National Semiconductor
Application Note 203
July 1978



A new four-bit slice "Schottky-coupled-logic" design combines the flexibility of the industry standard 2900 microprocessor architecture with advanced LSI processing. It implements low-power Schottky TTL circuitry on the same devices as a proprietary TRI-STATE™ emitter coupled logic design to achieve a 30 to 50 percent improvement in speed with no increase in power dissipation. It also allows the use of advanced "pipeline prediction" techniques in microprogram control design to significantly reduce microcycle times.

In most computer applications, cost, speed, power consumption and utility are the key factors. In some applications cost is the dominant consideration. In others it is speed or power consumption.

In bipolar four-bit slice microprocessor-based systems, this is particularly true. To date, however, designers have had to make a choice between the high speed of emitter coupled logic or the low power consumption and low cost of low power Schottky TTL four-bit designs such as the industry standard 2900 series.

But with current approaches it has not been very practical to have both.

If the designer chose an ECL design, he paid a price for the high speed with higher power consumption and loss of board design flexibility. If one of the LS bipolar 2900 designs currently available was chosen, low power could be achieved, but only at the price of considerably reduced system throughput.

Now, however, computer system designers can have both ECL-type speeds and LS bipolar power consumption. Using a new advanced "Schottky-coupled-logic" technique that combines low power Schottky circuitry on the same die as proprietary low power TRI-STATE ECL circuitry, the IDM2900 series of four-bit slice microprocessor components has been developed by National Semiconductor Corporation.

With this patented "SCL" technique, devices have been fabricated which are 30 to 50 percent faster than comparable 2900 designs now available. At the same time power consumption is slightly less than that for present LS bipolar designs and one third of that required for ECL-based designs.

The substantially increased system throughput made possible by this new series of SCL implemented IDM2900 parts means a number of advanced computer designs can be considered which were not possible before. For example, advanced "pipeline prediction" techniques in microprogram control design can be used to significantly reduce microcycle times.

An interesting byproduct of this approach is that this is the first ECL-based four-bit slice family to meet the military requirements over the military temperature range. Indeed, the new series shows even less performance degradation over the military temperature range than some of the standard LS bipolar parts now available.

A 60 Nanosecond Slice

The process and circuit improvement that have been achieved are the most apparent in the IDM2901, which boasts an average microcycle time of only 60 to 70 nanoseconds, a 100% improvement over existing LS bipolar designs. Power consumption, however, is about the same, only 800 milliwatts for the entire device. Also available is an even faster version — the IDM2901A-1 — with a microcycle time of only 50 to 60 ns, and no increase in power consumption.

As with other implementations of the 2900 architecture, the IDM2901 is the key element in this high speed family of four-bit slice components. Designed as a high speed cascadable element intended for use in CPUs, peripheral controllers, programmable microprocessors and numerous other applications, the IDM2901 consists of a 16-word by 4-bit two-port random access memory, a high speed arithmetic logic unit and the associated shifting, decoding, and multiplexing circuitry. (See figure 1.)

Indeed, except for that most important parameter — speed — the IDM2901 is plug compatible with any LS bipolar implementation of the same architecture now on the market. But plug in replacement and raw speed improvements are just part of the story. As can be seen from tables 1 and 2, the IDM2901, for example, has improved significantly almost every timing parameter possible. The read/modify/write cycle is 42 percent less, the maximum clock frequency 68 percent greater. Execution time for a typical operation, such as an add and shift (multiply) is 95ns maximum and 60ns typical, a significant gain over previous 2900 implementations. (See table 3.) Used in a typical design, system microcycle time is in the 100 to 150ns range, about one half to two thirds that of previous LS bit slice implementations.

These circuit and process improvements have been implemented in many of the standard components needed to build a system based on the 2900 bit slice architecture. In addition to the IDM2901, nine other standard parts have already been introduced. These will allow system designers to take advantage of the increased speed.

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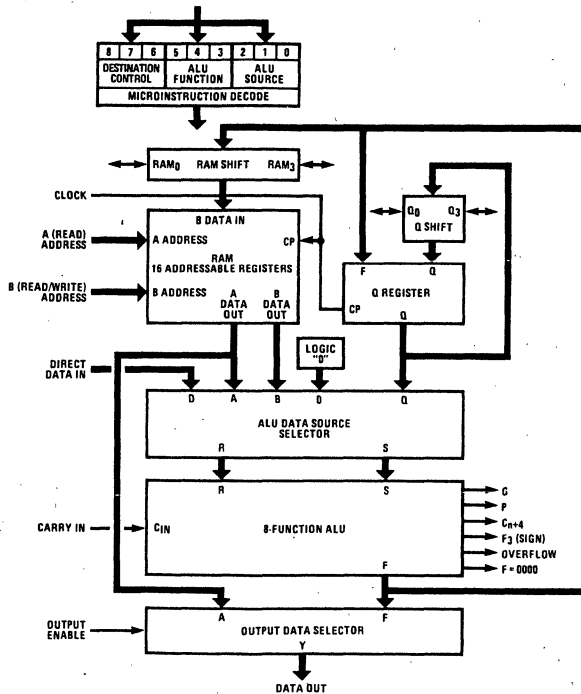


Figure 1. Block Diagram

Using some of the standard parts in the IDM2900 family, a typical 16-bit controller function can be implemented with a system microcycle time of about 140ns. This represents about a 30 percent improvement over that achieved with LS bipolar devices. Using the high speed IDM2901A-1, system throughput can be reduced to about 120ns. Using the proprietary parts added to the family, the same functions can be done in even less time, about 120 and 100ns, respectively.

Figure 2 shows a very simple, very fast state sequencing controller designed using IDM2900 family parts. It has no arithmetic capability, but 80ns clock intervals can be used. A less complex controller is shown in figure 3. It utilizes the IDM2901 for its data storage and arithmetic or logic generation. The IDM2911A is used as the state sequencer for this controller since its speed and subroutine stack can be used to advantage in the application.

LS + ECL = SCL

To achieve this combination of ECL speeds and LS bipolar power consumption, several techniques are used. One is to use low power Schottky circuitry in the periphery of the chip for input/output and interfacing to external TTL levels and the ECL internally — a technique commonly used in some bipolar memories. (See figure 4.)

Traditionally, ECL to TTL translators are slow unless considerable power is applied. In the IDM2900 family, however, the ECL speeds are retained, but at no cost in additional power, thanks to a TRI-STATE translator circuit technique that transforms the 0.7 volt ECL levels to 5 volt Schottky levels. This technique eliminates the slow and power consuming buffer transistors that usually do the job, and the translators can drop off to one third their active power with no loss in speed. Using this TRI-STATE translator technique, the extra 60 to 65 percent in power that would have been consumed is pumped instead into the portions of the device that require it; specifically, the ECL core circuitry.

Table 1. Percentage Improvement In Cycle Time and Clock Characteristics

Time	IDM2901A
Read-Modify-Write Cycle	40% less
Maximum Clock Frequency	6%
Minimum Clock Low Time	same
Minimum Clock High Time	same
Minimum Clock Period	40% less

Table 2.
Percentage Improvement
in Maximum Combinational Propagation Delays for IDM2901A and IDM2901A-1*

to Output from Input	Y	F ₃	C _{n+4}	$\overline{G}/\overline{P}$	F = 0 R _L = 470	OVR	Shift Output	
							RAM ₀ RAM ₃	O ₀ O ₃
A, B	19 (38)	19 (38)	13 (33)	8 (31)	22 (50)	24 (30)	26 (42)	
D (arith mode)	11 (29)	11 (29)	11 (29)	0 (14)	8 (47)	18 (27)	23 (46)	
D (I = x37)	0 (20)	0 (20)			0 (42)		17 (36)	
C _n	0 (17)	0 (27)	0 (20)		20 (40)	0 (17)	30 (30)	
I _{2,1,0}	0 (27)	9 (55)	0 (30)	0 (33)	14 (43)	23 (62)	20 (40)	
I _{5,4,3}	9 (30)	9 (30)	9 (30)	10 (36)	21 (43)	23 (31)	33 (40)	
I _{8,7,6}	0 (17)						0 (0)	0 (0)
\overline{OE} Enable/Disable	14/0 (43/20)							
A Bypassing ALU (I = 2xx)	11 (11)							
Clock	0 (17)	0 (25)	0 (25)	0 (20)	20 (33)	27 (27)	25 (31)	0 (0)

*2901A-1 in parentheses.

The output translators use both linear and digital techniques. Differential ECL signals are translated using a differential current amplifier where the differential output voltage is changed to a differential current and then back to an output voltage. This drives a phase splitting transistor used to, in turn, drive the output circuitry in the periphery. Key to the operation of these translators is the use of an improved TRI-STATE logic buffer circuit characterized by a current mirror transistor having its base and emitter, respectively, connected to the base and emitter of the phase splitter transistor, and its collector connected to the voltage supply terminal. (See figure 5.) The emitter size on the current mirror transistor is about twice that of the emitter size of the phase splitter transistor.

The current mirror transistor supplements the drive current that is provided by the phase splitter transistor to the pull-down output transistor. This permits a higher resistance to be connected between the voltage supply terminal and the collector of the phase splitter transistor without diminishing the drive current to the pull-down output transistor. By connecting a higher resistance, the power for the circuit is reduced when the output is in its disabled state.

An additional advantage realized as a result of the current mirror transistor base and emitter connected, respectively, to the base and emitter of the phase splitter, and its collector to the supply voltage terminal, is a faster dynamic response in the conduction state of the pull-down output transistor to a change in the level of the digital data input signal. This occurs due to the selective use of the Miller feedback effect to cause a beneficial ratio change in the current mirror pair during a dynamic transition. Miller feedback occurs on the phase

splitter transistor because its collector is coupled to the voltage supply through a resistance, and is absent on the current mirror transistor because its collector is directly connected to the voltage supply terminal. As a result, with the onset of the transition in the digital data input signal, as received from the collector of the input transistor, the current ratio between the current mirror and phase splitter transistors is even greater than the ratio of the respective emitter sizes.

Internally, the ECL logic has level translators on each input. This necessary circuitry achieves not only the level translation, but also has a very desirable input level sensitivity. As can be seen in figure 6, the translator is similar to a differential amplifier whose internal reference is stable. The result is very abrupt transfer characteristics on all input signals, and, thus, very fast switching speeds.

Improved Computer Design

The substantially increased system throughput made possible by this new series of SCL-implemented IDM2900 components means a number of improved bit slice processor designs can be considered which were not possible before.

Compared to simple control applications, there are a number of other factors to be considered when using IDM2900 series devices in more complex processor systems. The general changes which take place relate to special handling of data and address outputs and data inputs. The IDM2901's register and ALU elements are no longer sufficient, especially when data and address word lengths grow from 8 to 16 bits or greater. Special functional elements are generally added, and include: input and output data or addressing registers, sign extend of

Table 3.
Maximum Throughput Comparisons for Add and Shift

Function	IDM 2901A-1	IDM 2901A	AMD 2901A	AMD 2901
A or B $\rightarrow \bar{G}$ or \bar{P}	45	60	65	80
74S182 Delay	10.5	10.5	10.5	10.5
$C_{IN} \rightarrow RAM_0$	35	35	50	55
RAM Setup Time	15	20	25	55
Total	105.5	125.5	150.5	175.5
Percent Change	40%	28%	14%	0%

data, and instruction decode, as well as shift and rotate control, and multiply functions. Also, special processor status registers are quite often added, as well as the unique controls for these elements.

Some special thought applied to these areas can reduce the parts count considerably and improve processor performance when using IDM2900 components.

The sign extend function is a good example of what can be done. Sign extension of a data word can be accomplished in a number of ways. But what the designer of the processor would prefer is to implement the function with the fewest possible parts and at the fastest data inputs. The first solution that comes to mind is the use of multiplexers, as shown in figure 7, which allows data to be fed through the multiplexer to D inputs of the IDM2901's. The control function which steers the data to the D input representing the bit which needs to be extended normally comes from the microprogram store. The added delay using this path is 12ns or more if parts slower than the DM74S157 are used. For each 4 bits of data to be modified an additional component is required; 2 parts for 8 bits, 3 parts for 12 bits and 4 parts for 16 bits.

The IDM2900 family, however, allows consideration of a number of other ways to do sign extension that require fewer parts and are less expensive and faster.

One is to use the carry input to accomplish a sign extend. But to use this input one must subtract "1" from "0" conditionally if the sign bit is a "1" and the opposite if it is a "0." But the problem arises as to how to obtain a value "0" in a register, an impossibility.

But the same effect can be achieved if the same address location is placed upon both the A and B address inputs. The source code is then used to select A and B and the function code for subtract. Now, if a carry input is a "1" the result is a "0" and if the carry input is a "0" the result is an all "1s" sign extend result. This technique can propagate for as many packages as necessary since the carry logic is necessary for other functions and is already included.

An easy method of inserting the conditional carry with the IDM2901 is to use the IDM2902 in a manner that is different from standard LS bipolar designs. Instead of connecting the carry input of the 2902 to the microcontrol carry from ROM, it is connected to the carry out of the least significant IDM2901 package. Note that this is just as fast as the previously suggested connections since the G and P are only slightly faster than the carry out of the least significant IDM2901. Doing this allows one free G and P input to be available at the second level, as indicated in figure 8.

It is only necessary to connect an AND gate to the input and sign extend is accomplished. The lower bits which want to be entered without modification need only be applied to the D inputs and a source code selected to perform a D minus 0 transferred to B. The most significant package group produces A minus B where A and B are as described before. An all-1s or all-0s result is obtained dependent upon the value of the data bit to be extended. The result is a sign extension with three fourths of a package for any sign extend, achieved at no loss in normal cycle time. This is because a carry input change can occur later in a cycle than a change of D.

Performing a Multiply

Most of the time the name of the game in computer processor design is speed. Nowhere is this more true than when it is necessary to perform a multiply. This is because the multiply determines the longest cycle time if performed in the normal manner. This is because more than one path through the 2901 is utilized. Passage through several external components is usually required and this must also be added to the solution time. However, with the use of high speed components in the IDM2900 family it is possible to circumvent and shorten this path, and thus shorten the multiply cycle time.

How this is done is clearly understood only by referring to a specific example. Let's assume the problem is to perform a multiply of two signed 16-bit values.

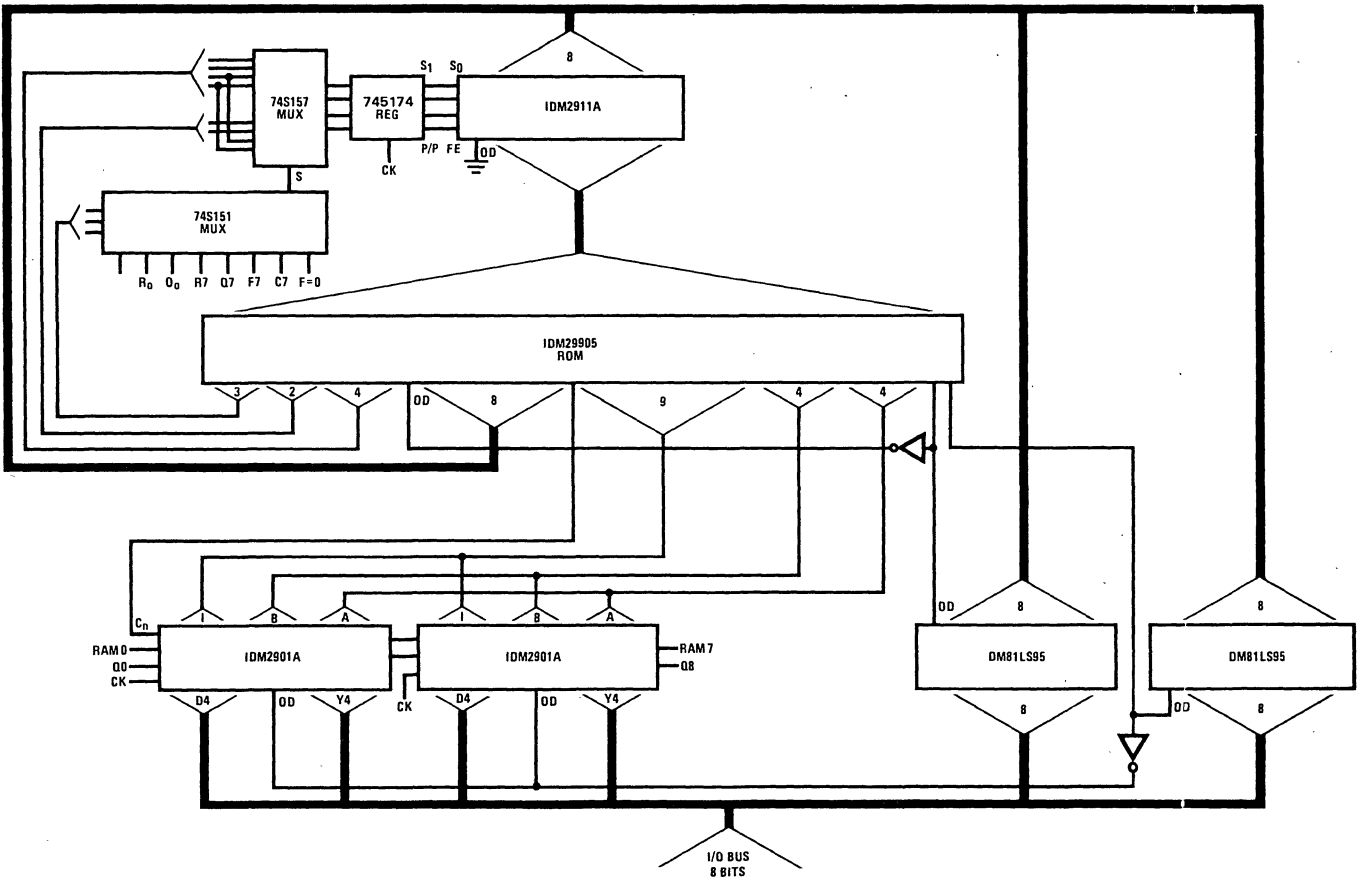


Figure 2. Very Fast State Sequencing Controller

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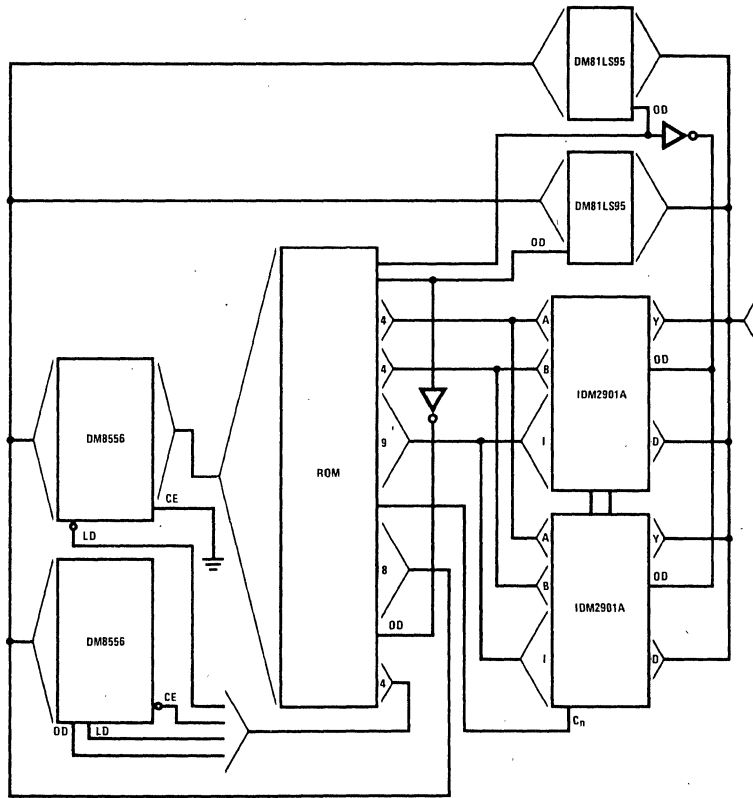


Figure 3. Small High Speed 8-Bit Controller with One Level of Subroutine Capability.
This solution can run at 100ns cycles.

Figure 8 is the circuit as implemented using IDM2900 devices with the two multiplexers (74S253) and a D flip-flop (74S74). Using IDM2900 components and this technique, the multiply is performed 30 to 70 nanoseconds faster per cycle than with standard LS bipolar bit slice parts. This is a total speed improvement of 480 to 1,120ns.

An additional significance to the design is that special multiply cycle time intervals are not required. This operation, therefore, makes possible a processor or controller with a less complicated clock control circuit.

Note that in figure 8 there is an extra stage of register storage in the Q register (D type flip-flop), compared to traditional designs. It is therefore necessary to shift Q one time without shifting the file register.

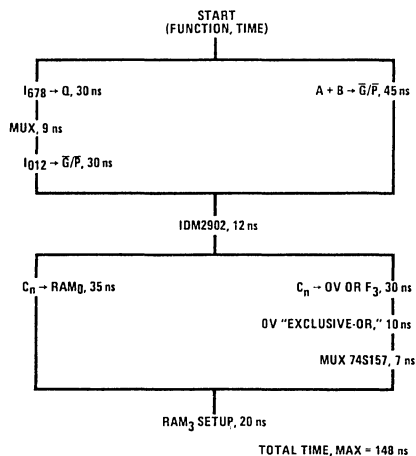
Since it is necessary to clear the partial product register, the Q register is shifted the first time so as to get the least significant bit into the extra storage location.

After this, the A and B register file addresses do not change and therefore do not enter into the timing equations. The much faster response time of an added D flip-flop saves a great deal of time in each microcycle of the multiply add and shift operation.

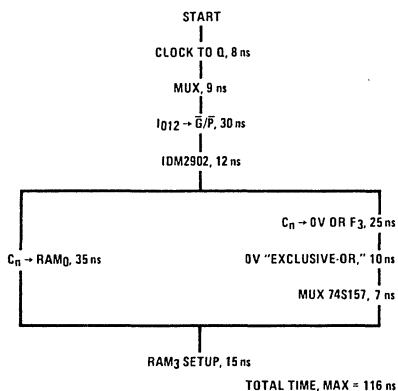
Since the A and B inputs do not change the critical path is from the D register output into the I_{O12} inputs and through the IDM2901As in a normal add and shift operation. Using the Q flip-flop, 20ns is saved, and using the I_{O12} input, 10ns is saved in each of the 16 cycles of the 16-by-16 multiply. This is all that is necessary for a positive signed multiplicand. But if a negative result is required, an additional path must be added.

The two possible paths in the most significant IDM2901A package are from C_n to RAM_0 output or from C_n to Overflow or F_3 and through the additional exclusive-OR gate and multiplexer input to the RAM_3 input. The maximum time delay path is 20ns from overflow and F_3 outputs back to the RAM_3 input for the most significant 2901A package.

Using standard techniques common to previous 2900 designs, only 15 conditional adds, followed by a shift and one conditional subtract and then a shift, are required to do a signed multiply in 2s complement notation. The resultant data paths required for this solution are as follows:



But if the circuit described in figure 8 is used, and the A and B address lines are set up one cycle ahead of the multiply sequence, the following timing comparison, using IDM2901A-1s instead of IDM2901As, prevails:



A net savings of 32ns per microcycle is thus achieved with this change. It can now be seen that sometimes it pays to add a flip-flop in certain locations to achieve higher performance so as to achieve a simpler solution in other areas. Here, a 20 percent reduction in cycle time was achieved.

Improving Microcycle Times with Pipeline Prediction

Perhaps the most important aspect of National's IDM2900 family of high speed, low power SCL components is the impact on how microprogram state sequencing is implemented in bit slice designs. The ultimate result will be further improvements in microcycle times beyond anything now possible with present 2900 bit slice families.

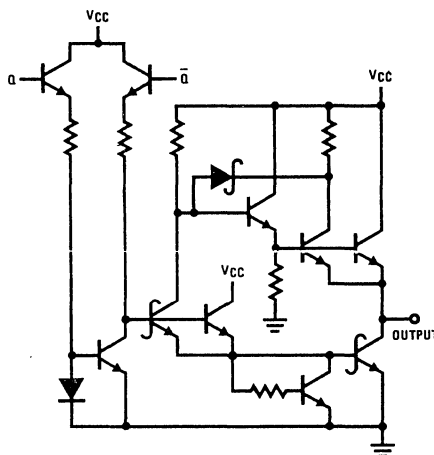


Figure 4.

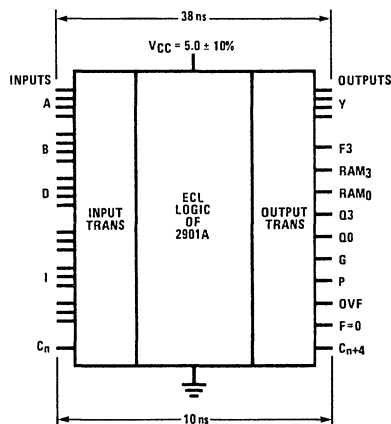


Figure 5.

In the very earliest use of state sequencing — in minicomputers and larger systems — operations were performed in series, one after the other, and the microcycle was defined as the sum of the operations. (See figure 9.) Still in use in some designs today, in this approach a state sequencer increments to the next state or branches to a next state depending on the logic level of the test input. In this solution the controller timing is from the clock edges of the controller register/counter through microcontrol storage (ROM) and the processing elements (2901s), then back through the next state decision tree to the controller-register counter.

The second approach is called "pipeline microcoding," and is an approach commonly used in bit slice systems such as the standard LS bipolar 2900 family. (See figure 10.) In this solution the microcontroller loop timing is operating in parallel with the execution of the processing component section.

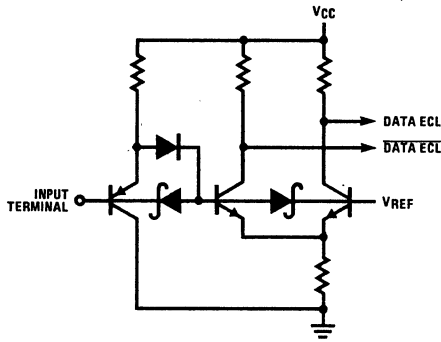


Figure 6.

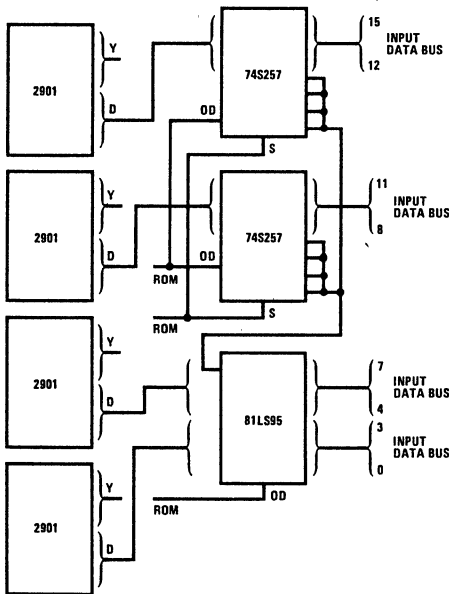


Figure 7. Sign Extend Using Multiplexers

During the time an arithmetic operation is being performed, the next microcontrol word is being set up for use by the microcode. The microcode for the present register/ALU operation occurs during the previous operation. The use of the register between the output of the microcontrol store and the 2901s allows the two sections to function with overlapped timing. The result of this type of micro-sequence control is a faster machine cycle time than used in the totally serial mode of operation.

Also required in this mode of operation is the absolute knowledge of the next state control one cycle before the execution of the 2901 cycle. It is therefore difficult to implement a number of successive conditional next state decisions. This type of microcontroller is said to be operating in a "pipeline" mode in that the next state microcontrol is being obtained during the time the previous one is being executed.

Using SCL-implemented IDM2900 components instead of LS bipolar bit slice devices in this approach results in a 65 to 75 percent reduction in the register/ALU portion of the microcycle. In spite of this, total microcycle time may be reduced only 40 to 50 percent. This is because the microcycle time is determined by the length of the longest operation, which in this case can be the delay in the microcode portion.

To get the full benefit of the high speeds inherent in National's SCL family therefore means abandoning the traditional approach to pipelining used in previous 2900 bit slice designs. What can be used instead is a different technique — pipeline prediction — which allows a reduction in the microcode portion of the microcycle so that it is equal to or less than the register/ALU setup time. The relative timing comparisons between these four approaches are shown in figures 11A through 11D.

The "pipeline prediction" controller functions in much the same way as the standard pipeline configuration except that it can also accept any number of successive conditional next state decisions in a row. This microcontroller "pipelines" microcontrol sequences in much the same manner as the previous design and for the same reasons. But shorter microcycles can be obtained due to the fact that during any microcycle the most predictable next cycle is being set up. But should the test of the next state decision be different from the one predicted, then the alternate state is conditioned and the microcontroller and the data system pass through a correction interval.

This design makes next state decisions within the same cycle as microcontrol of the IDM2901. Figure 12 shows a "pipeline prediction" technique where the next state is a choice between two states. This means one state is predicted, and if incorrect the second choice is used. The microcycle is either delayed or an additional cycle is inserted.

There is no real reason why the design must be limited only to two next state conditions. Any number may exist. It is only necessary to predict the most probable next state and correct it if necessary. Most next state decisions are known to a high probability of occurrence. The additional cycle time added for the few times an incorrect prediction is made is extremely small compared to the total microcycle time saved. Additional speed is obtained with this technique since it minimizes the number of states through a control sequence.

Finally, pipeline prediction requires no increase in the number of components to achieve these increases.

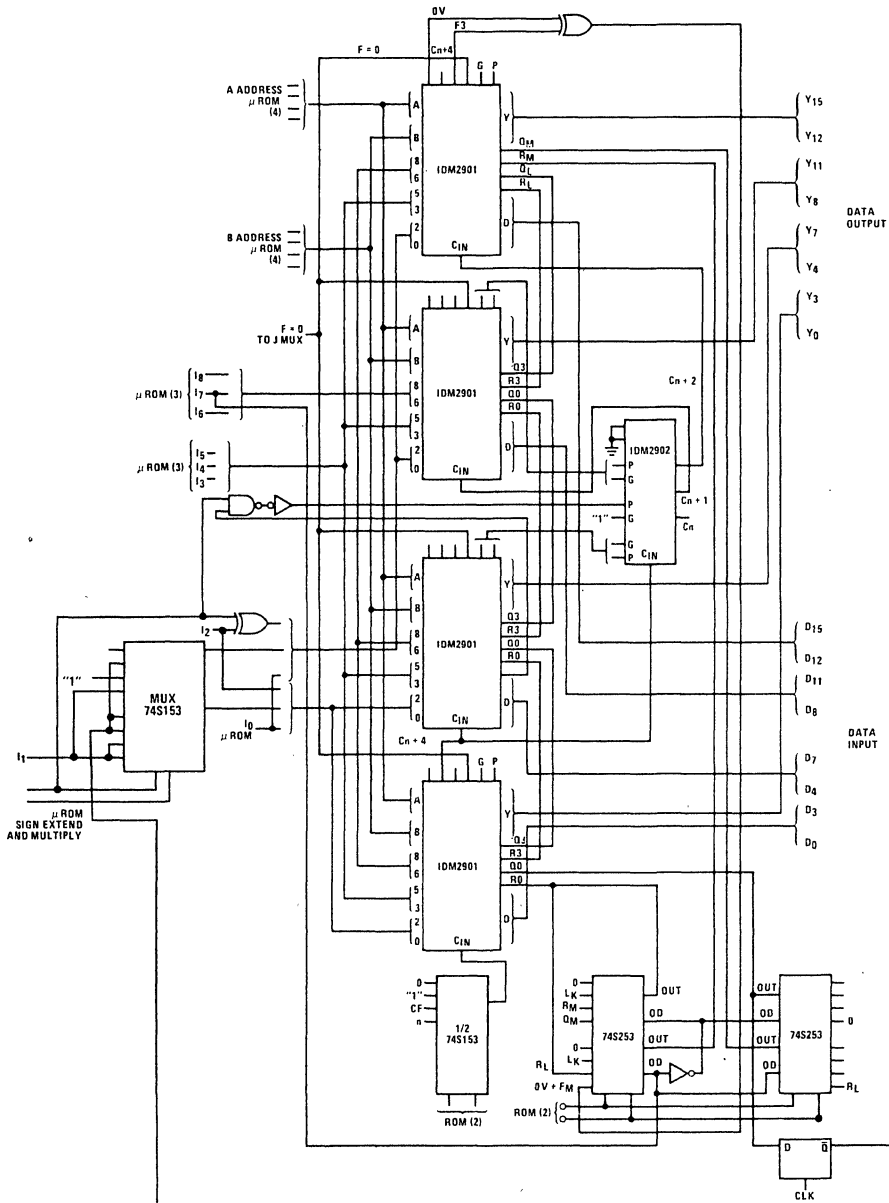


Figure 8. 16-Bit Register/ALU Design

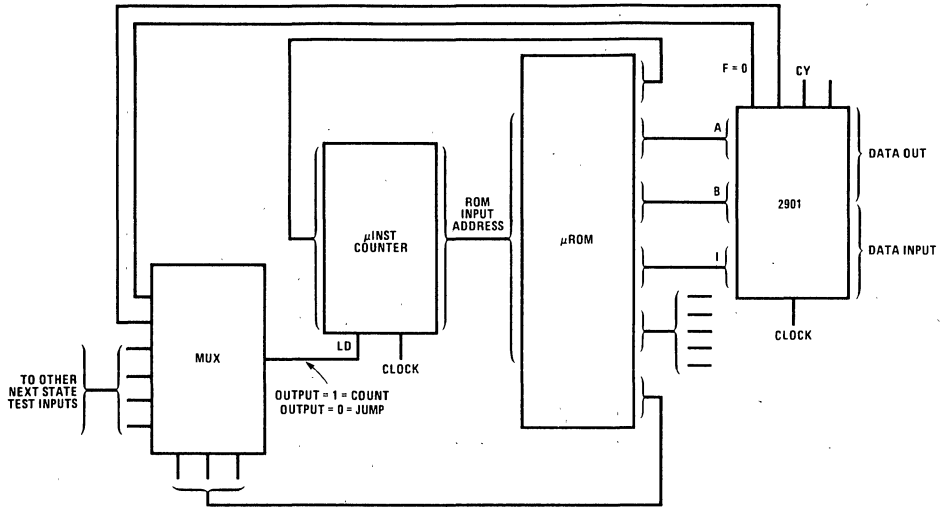


Figure 9. The Simple Microcontroller

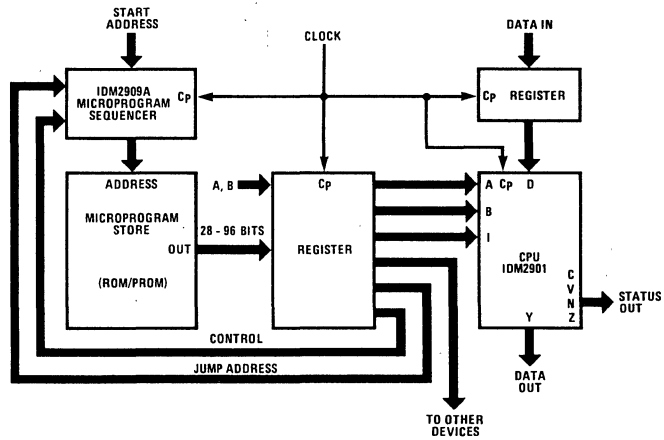


Figure 10. Microprogrammed Architecture Around IDM2901s

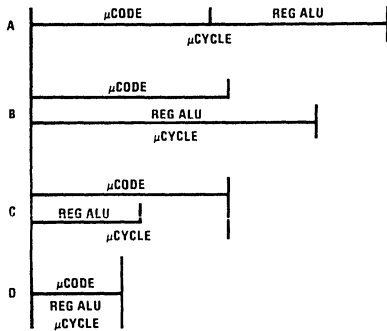


Figure 11. History of the Microcycle

Future Trends

By using higher speed parts such as the IDM2901A-1, greater improvements in throughput are possible.

And in the future there is the possibility of even further improvements, particularly on the chip processing level. The present components in

National's IDM2900 SCL family have been designed with exceedingly liberal design rules. In spite of that, the chip area on the IDM2901, for example, is equal to or less than that of some of its LS bipolar counterparts.

What this means is that there is inherent in the SCL technique the possibility of further improvements in density and integration — combining of many bit slice functions onto fewer and fewer chips — while maintaining speed.

It's not unreasonable to expect speeds on SCL-type bit slice 2901A parts to be in the 40 to 50ns range by the end of the decade and system throughput figures to be in the 80 to 90ns range. Even though SCL microcycle times at the component level may not match pure ECL-implemented parts, the system improvements allowed by the lower power may ultimately result in the design of systems with throughputs far in excess of what is possible with emitter coupled logic — at much lower power and cost.

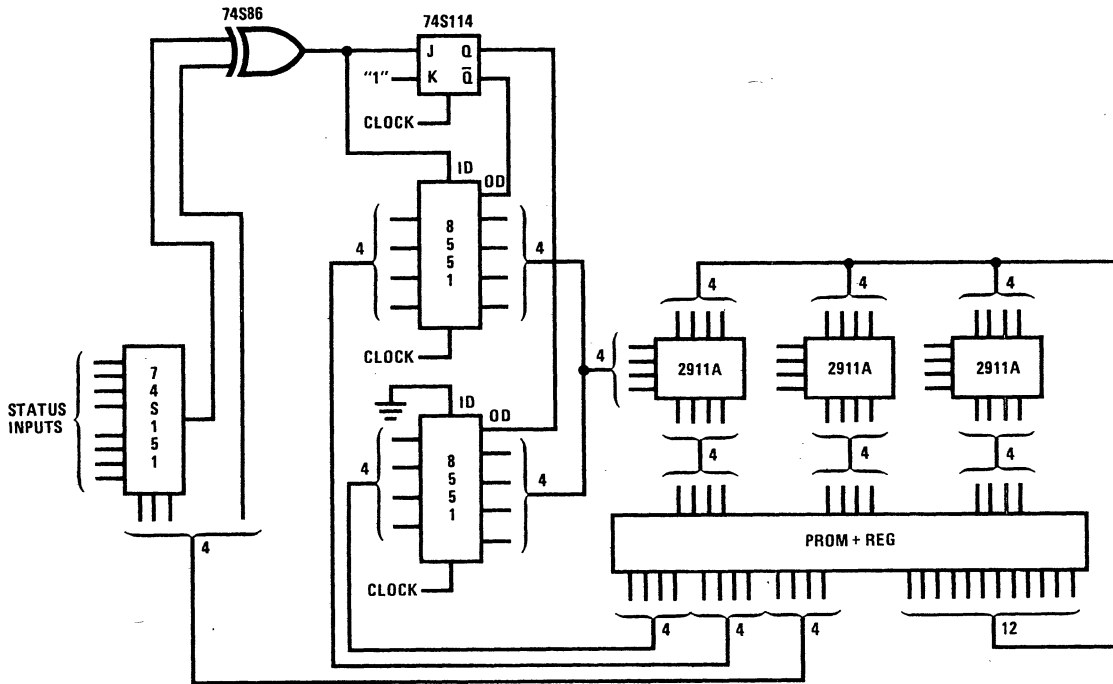


Figure 12. Microsequencer Controller for Pipeline Prediction



High-Speed Bit Slice Microsequencing Design

With the advent of higher speed versions of the industry standard 2900 bit slice microprocessor family, numerous options are now available to the system designer.

Using traditional approaches to bit slice system design, even the simple replacement of low speed, low power Schottky devices with a higher speed part, such as the IDM2901A-1, means an improvement in system throughput of 30% to 50% (Tables 1A and 1B). More importantly, these high speed parts mean a number of advanced computer designs can be considered, resulting in greater flexibility in making design tradeoffs between speed and parts count.

Table 1a. Maximum Cycle Time to STATUS Outputs*

Function	IDM2901A-1	IDM2901A
2901A A or B to \bar{Q} or \bar{P}	45 ns	60 ns
74S182 \bar{Q} or \bar{P} to Carry Out	7 ns	7 ns
2901A C_{in} to F0, F3, C4 or OVR	30 ns	40 ns
Total	82 ns	107 ns

*Add applicable pipeline register timing.

Table 1b. Maximum Dedicated Signed Multiple Cycle (Conditional Signed Add and Shift)

Function	IDM2901A-1	IDM2901A
74S74 Clock to Out*	9 ns	9 ns
2901A I1 to \bar{Q} or \bar{P}	30 ns	45 ns
74S182 \bar{Q} or \bar{P} to C Out	7 ns	7 ns
2901A C_{in} to F3 or OVR	25 ns	30 ns
74S86 Propagation Delay	10.5 ns	10.5 ns
2901A RAM Setup	15 ns	20 ns
Total	96.5 ns	121.5 ns

*Use a 74S74 as Q0 output, then connect inverted 74S74 output to I1 to realize a 19 ns saving.

To take advantage of these high speed parts, an equally fast microcontrol loop is required, so that this portion of the system is a help and not a hindrance in increasing total throughput.

A number of microcontroller loop circuit configurations have been developed to take full advantage of these high speed parts. The choices are by no means

exhaustive. Their purpose is to serve as an example for the designer; a starting point from which new designs can be developed.

MICROCONTROL AND THE MICROCYCLE

The object of the microcontrol portion of a processor or controller is to access the next control word to be used by the register/arithmetic-logic unit. The microcontrol portion includes a microstore of control words and a next state sequencer. Control words are fetched from microstore addresses as selected by the next state sequencer. Microstore addresses may be generated by incrementing, branching, etc., the next state sequencer being directed by a portion of the control word and by the logic level of a test input.

The microcontrol portion has to set up the next control word as quickly as possible, but otherwise stay out of the way, allowing the register/ALU portion to run at its maximum speed.

Today, this is not as easy as it was in the past. With LSI register/ALU units, such as the IDM2901A-1 or the IDM2901, capable of speeds in the 100 to 125 nanosecond range, even the most complicated operations, such as multiply and divide, are fast enough to push most present day microcontroller designs approaches to their limits. Therefore other, higher speed approaches must be considered to take full advantage of the higher speed register/ALU's.

The first approach to microprogrammed system design — the very earliest use of state sequencing was utilized in early minicomputers and even some larger systems. Operations were performed in series, one after another (Figure 1 Phase I), with the microcycle being defined as the sum of the separate sequencer and register/ALU operations.

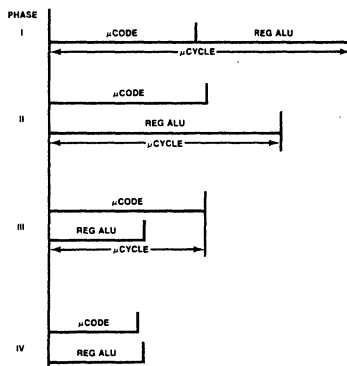


Figure 1. History of the μ Cycle

This solution, still in use today in some designs, routed controller timing from the clock edge of the controller register/counter through microcontrol storage, through the processing elements, then back through the next state decision tree to the controller register/counter.

The second approach, called pipeline microcoding, is an approach commonly used in bit slice systems. In this solution the microcontroller loop timing operates in parallel with the execution of the processing component section (Figure 1 Phase II). During the time an arithmetic/logic operation is performed, the next microcontrol word is being accessed. The microcontrol word for the present register/ALU operation had been selected and accessed during the previous microcycle, and is currently held in a pipeline register.

This type of microsequence control results in a faster machine cycle than is achievable in the totally serial mode employed in the first approach. It may not however, achieve machine cycle times consistent with the register/ALU cycle times available with today's higher speed register/ALU elements. For example, using highspeed components, such as the IDM2900 family, results in a 65 to 70 percent improvement in the register/ALU path. In spite of this, the resultant total microcycle time may be reduced only 30 to 50 percent because the microcycle is determined by the duration of the longest operation, which, in this case, is the delay required by the microcontrol portion (Figure 1 Phase III). Circuits optimized to approach the register/ALU cycle time (Figure 1 Phase IV) are required.

Another problem associated with pipelining is that it also requires absolute knowledge of the next state control one cycle before the execution of the current register/ALU cycle. Therefore, it is difficult to implement successive conditional next state decisions which require a test of current register/ALU results. This problem will also be considered.

As will be shown, different circuits may be configured to minimize microcontrol delay while retaining the benefits of bit slice use. While the pipelining approach will be used throughout, the circuits will differ in the manner in which conditional branch control is achieved. Speed and parts count are traded off, while retaining the same microsequencing instruction set.

Three modes of executing conditional branches are covered:

1. Overlapping the conditional branch propagation with the execution of a next unconditional microinstruction and using a NOP microcycle whenever useful work cannot be done in parallel (a NOP is a No Operation microcycle during which the register/ALU is prevented from changing its contents). Conditional and unconditional microcycle times are equal.
2. Using the same sequences as above but employing different microcycle durations; a shorter one for unconditional microinstructions and a longer one to allow for the propagation of conditionals.
3. The pipelining prediction mode, where the conditional branch test is overlapped with the propagation of its statistically most likely outcome. Should this prediction prove to be true, the sequence continues; if false, a "pipeflushing" (NOP) one-cycle

time delay is employed, during which the correct control word is allowed to propagate to the microcontrol output.

BASIC CIRCUIT ASSUMPTIONS

In all cases it is assumed that the machine has a 16-bit register/ALU and a 12-bit microaddress. Changing these parameters may increase or decrease the relative value of a given circuit.

The following constant time delays will be assumed in all circuits:

1. Microstore Time Delays

A microstore access time of 50 ns and a pipeline register setup time of 5 ns are assumed. (This is the minimum time required between microaddress validation and clocking the pipeline register).

2. Microsequencer Time Delays

The "select address" propagation time of the microsequencer is the time interval beginning when the select lines become valid and ending when the desired microaddress is available at the microsequencer's outputs. Using the high speed IDM2909/11A, a select time of 30 ns is guaranteed along with a 45 ns clock to output (from file) time.

Thus, the longest total path for the microstore plus the microsequencer is:

$$50 + 5 + 45 = 100 \text{ ns}$$

This delay represents the calculated limit of the minimum time required to perform any unconditional sequence.

The setup time required by the microsequencer's internal registers is easily met in a 12-bit configuration, since it calls for a delay time of

$$(S_0 S_1 \text{ to } C_{n+4}) + (C_n \text{ to } C_{n+4}) + (C_n \text{ setup}) = 68 \text{ ns}$$

which is overlapped by the delay required between $S_0 S_1$ and the next system clock.

The condition-test time delay is circuit dependent and will determine how fast, or how slow, the circuit will go.

This delay includes: 1. the time required for the pipeline register to become valid from clock; 2. the selection or propagation of the status bit under test; 3. the negation or assertion of its polarity, and; 4. the translation of the test result and conditional branch data to code compatible with driving the microsequencer.

Since the choices in selecting fast microsequencers and microstores are severely limited, the condition-test circuitry becomes the prime candidate for user optimized logic designs, because it is simple and inexpensive, etc. The following circuits attempt to minimize, in different ways, the "delay" overhead caused by the next state decision. To gain a measure of their relative speeds, the delays are compared to the calculated minimum for unconditional sequencing,

which is 100ns. A figure of merit is derived by dividing the total time delay by 100ns minimum (Table 2).

Table 2. Microcontrol Circuits Comparison

Circuit	Dynamic Performance	Figure of Merit	Parts Count	Relative Cost
I	158ns	58%	6 1/4	1.00
II	(Note 1)	(Note 1)	3 1/4	1.72
III	117/166ns	17%/66%	7 1/4	1.12
IV	114/135ns	14%/35%	7 1/4	1.10
V	133ns	33%	7 2/3	0.96
VI	108ns	8%	5 3/4	0.90
VII	108ns	8%	6 1/4	0.97
VIII	108ns	8%	7	1.06

Note 1: The presently (October 1978) available 2910 has a published guarantee of 100ns from clock to Y output on instructions 8, 9 and 15.

The longest data path has not been released. It occurs where prior instructions were 4 or 12 or RLD was low.

The currently available 2910 will need a 207ns cycle when used in Circuit II in order to accommodate its longest data path (using calculated guarantees based on lab measurements performed on a number of parts). The corresponding figure of merit is 107%.

National Semiconductor's IDM2910A will need a 133ns cycle in the same circuit for its longest data path. The figure of merit will be 33%.

The IDM2910A will become available during the third quarter of 1983.

CIRCUIT I

This circuit is the traditional approach to the implementation of the microcontrol loop in a pipelined

configuration. Status outputs of the last register/ALU operation determine the micro-control word to be used for the next register/ALU operation.

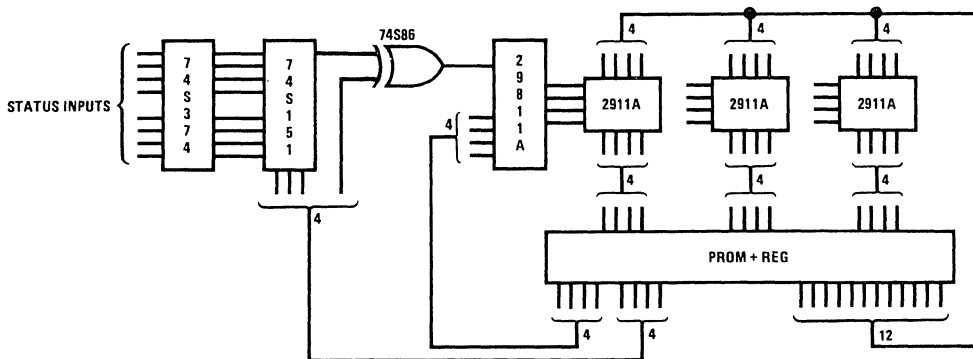
An IDM29811A next address controller is used to apply next address control to the IDM2911A four-bit micro-program sequencers. The IDM29811A is controlled by four pipeline register bits and one test input. The line to be tested is selected by a 74S151 eight-bit MUX as determined by the pipeline register. The pipeline register also determines whether negation or assertion should be performed by the 74S86 XOR gate to make it compatible with 29811 logical requirements.

The lines to be tested (inputs to the MUX) may be the results of a variety of functions internal or external to the controller. One line is generally tied to a permanent logic "1" or "0" so that by selecting it, the pipeline register may generate unconditional control of the 2911A. Some of the tested lines may carry data generated towards the end of the microcycle, such as ALU status. These data are stored in a 74S374 TRI-STATE® octal D type flip-flop since it has to be used in the next microcycle.

Conditional microcycles may be either overlapped with useful work (microprogram permitting) or may be waited out by means of a NOP. Total microcycle length required by this microsequencer is 158ns and the figure of merit is

$$\frac{158 - 100}{100} = 58\%$$

A comparison between this microcycle time (158ns) and the register/ALU loop time of 125ns or 105ns for the IDM2901 or IDM2901A-1, respectively, reveals that the machine's speed is limited by the microcontrol circuit. In short, even though the fastest microsequencer component (IDM2911A) was used, this traditional approach to microsequencer design is not compatible with higher speed, state-of-the-art ALUs.



Microcontroller, Circuit I

CIRCUIT II

One immediate "solution" to the problem outlined above, that has been suggested by some manufacturers, is going to a higher level of device integration, such as the 2910, which is a 12-bit microprogram sequencer designed to replace the 2911A and 29811A.

Conditional microprogramming is achieved here in the same way as in Circuit I and the parts count is reduced by 50%. However, the longest delay path is the one from the clock through the register/counter load to output — a guaranteed value of about 100ns. Microcycle time of this circuit is 207ns,* its figure of merit is 107% which is worse than the circuit it was designed to replace. The reduction in parts count, however, may be beneficial in those applications where operating speed is less important.

CIRCUIT III

This circuit utilizes two different clock cycle periods: a short one for unconditional sequencing and a longer one for conditional sequencing. A 74S157 quad two to one MUX and one additional pipeline register bit are used in order to provide faster, unconditional next address control for the 2911As. When conditional control is required, the path selected by the 74S157 will go through the 29811A. The four pipeline register lines will switch from carrying 2911A code (unconditional) to carrying code needed for the 29811A. Conditional microcycles need to be achieved by a clock extended microcycle which can either be overlapped with useful work or waited out with a NOP.

Total unconditional microcycle time is 117ns and the figure of merit is 17%. For the conditional microcycle mode, total time is 166ns and the figure of merit is 66%.

The overall figure of merit can be determined by weighting the calculated percentages according to the relative dynamic frequency of conditionals.

CIRCUIT IV

Similar to Circuit III, this circuit differs only in the replacement of the 29811A and the 74S157 with two 74S158 quad two line to one line multiplexers. Inverting outputs have been chosen to gain speed.

Two 4-bit pipeline register fields are supplied to the condition selected 74S158, one of which is used in unconditional microsequencing by the 74S158 that drives the 2911A.

This solution produces cycle times of 114ns and 146ns and figures of merit of 14% and 46% respectively, for the unconditional and conditional next state cycles.

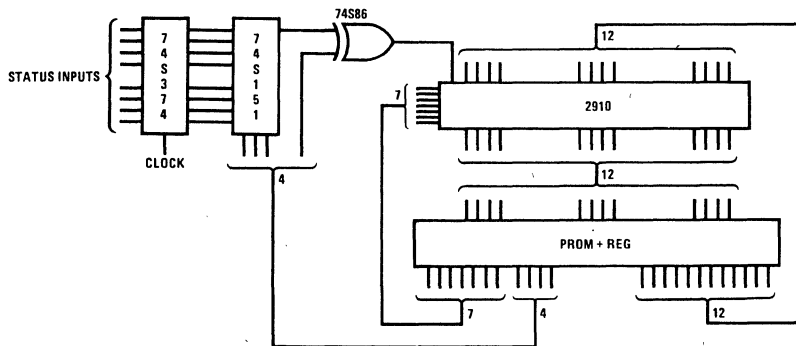
Now, by positioning the contents of the two 4-bit pipeline fields according to the logic level expected on the line under test, it is possible to remove the 74S86, eliminate one pipeline register bit to save 11ns on the conditional next state cycle. This reduces the time to 135ns and the conditional figure of merit to 35%. The unconditional figure of merit is unchanged (14%). Microprogramming is similar to that of Circuit III.

Another variation of this circuit is possible by removing the 74S158 driving the 2911A and connecting the outputs of the remaining 74S158 to the 2911A. The 74S86 may also be removed since the two, 4-bit pipeline register fields can be positioned to anticipate the desired result. Unconditional microcontrol is achieved by placing the same data on both sides of the 74S158. Total microcycle time is 129ns for both conditionals and unconditionals and the figure of merit is 29% (Compare this to the constant-microcycle time Circuit I and II). Microprogramming is the same as in Circuit I.

CIRCUIT V

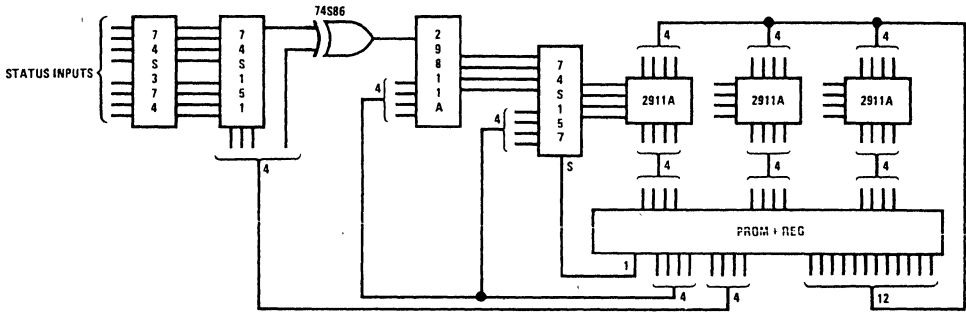
This circuit illustrates in yet another way the flexibility and advantages obtained by mixing MSI and SSI, in this case replacing the 74S158's used in previous circuits with 74S151's. Total timing needed is 133ns with a figure of merit of 33%.

This circuit is included to demonstrate a principle: sometimes a faster dynamic performance can be obtained by not using more complex circuits, in this case PROMs (29811A) and multiplexers. This occurs because less complex circuits allow greater freedom of design as well as being faster. Complex circuits may be slower and they frequently "force" design solutions to fit their own logical structure. Compare this circuit to Circuits, I, II and III.

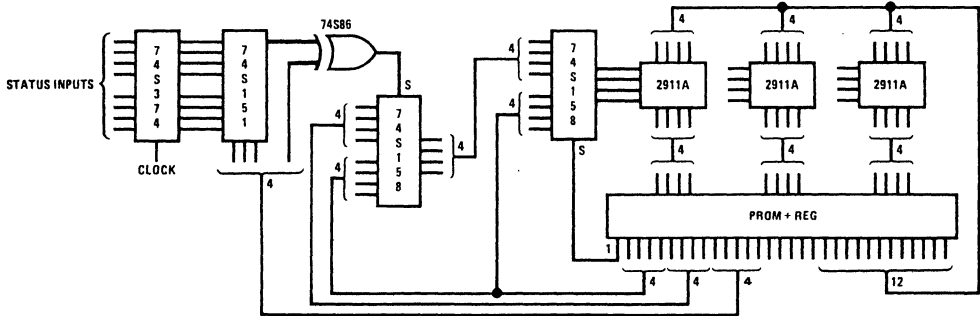


Note: Calculated guarantee based on lab measurements performed on a number of presently (October 1978) available parts. National Semiconductor's IDM2910A will show a significant speed improvement. (See Table 2.)

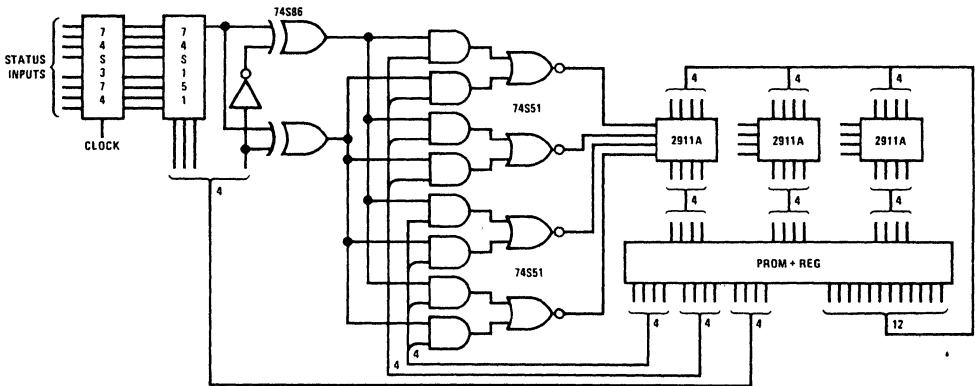
Microcontroller, Circuit II



Microcontroller, Circuit III



Microcontroller, Circuit IV



Microcontroller, Circuit V

CIRCUIT VI

This circuit represents a conceptual departure from the previous circuits. Although it functions in the same manner as the other circuits, here register/ALU performance is traded off in favor of the microcontroller loop. In other words, certain control loop time delays have been shifted over to the register/ALU loop. The status line to be tested is selected on the same microcycle that originated the status. One 74S74 edge triggered FF is used instead of the 74S374's which appear in the previous circuits.

In effect, the status register is now only one Flip-Flop of a faster variety than the 74S374's and less expensive relative to package count. If conditionals are performed by setting the two 4-bit pipeline register fields to be identical to each other, the 74S86 may be removed as in Circuit IV.

Microcycle time is 108ns and the figure of merit is 8% for both conditional and unconditional sequences. It should be remembered, however, that 15ns has been inserted into the register/ALU loop. Using the 2901A-1, this 15ns must be added to the status valid time for a 16-bit addition of 82ns plus a 9ns clock-to-output pipeline register on the file addresses. This gives a total register/ALU microcycle time of:

$$82 + 9 + 15 = 106\text{ns}$$

which is compatible with the 108ns required for the microcontroller portion.

If the overall solution can be improved by moving time from one loop to another, the designer should do it.

Microprogramming this circuit is slightly different than the previous circuits since status generation and selection must be made during the same microcycle. Overlapping conditionals with useful work can be accomplished, or NOPs could be employed.

CIRCUIT VII

This circuit employs pipeline prediction to enhance speed in performing conditional microsequences.

Since in the other circuits outlined, the results of a register/ALU operation cannot be used to direct the operation immediately following it, it becomes necessary to insert fill-in words or NOPs. Pipeline prediction will minimize the number of NOPs required.

The term "prediction" refers to selecting and propagating the statistically most likely outcome. Should this prediction come true, the machine will continue at the unconditional microinstruction speed. If, however, the prediction turns out to be wrong, the predicted microcycle is converted to a NOP while waiting for propagation of the correct conditional outcome. During this waiting period the system will ignore the false microcontrol output word.

In this circuit, the prediction (and its correction, if necessary) are controlled by a 74S114 J-K edge triggered flip-flop. A logical zero result at the 74S86 output leaves the 74S114 in the "predict" position; a logical "one" causes the device to toggle and to apply to the 2911A the other choice of control code. This code is found in the 74S374, which is used as a one

microcycle delay in order to preserve the initial code during NOP execution. Microcode forces a zero logic level at the output of the 74S86 whenever unconditional microinstructions are used. This logic level, in turn, causes the 74S114 to remain in its "predict" state, which is also used to generate unconditionals.

With this design, it is possible to stack any number of conditional states next to one another without confusing the controller. If all the predictions are correct, the machine operates in half the number of cycle times than with the previous technique. If all the first choices were incorrect, the design still breaks even with the previous solutions.

Generally, a net savings of cycles will result, having the same effect as an additional microcycle time speedup. This, together with the employed single length clock, makes this a very attractive circuit.

Microprogramming this circuit resembles Circuit VI, except that a jump (JMP) may not be predicted if the other choice is a continue (CONT). Such a prediction would cause an irreversible change in the microprogram counter/register. Other changes that may occur in the 2911A stack or address register can be inhibited by using the "one" logic level at the 74S86 output as a means to inhibit the RE and FE lines.

Total microcontroller cycle time is 108ns and the figure of merit is 8%.

CIRCUIT VIII

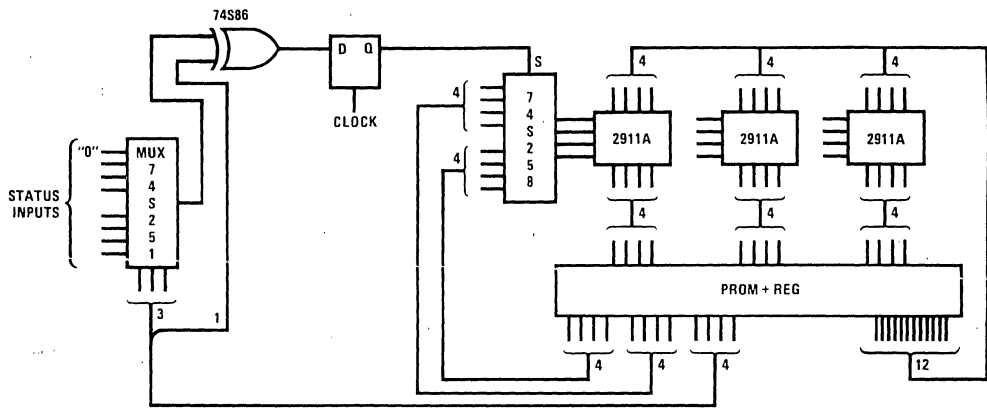
This circuit is essentially the equivalent of Circuit VII. Two 74S251 TRI-STATE[®] multiplexers have been used to decrease the propagation delay on the register/ALU side by eliminating the 74S86. Total time and overhead are unchanged (108ns and 8%).

CONCLUSION

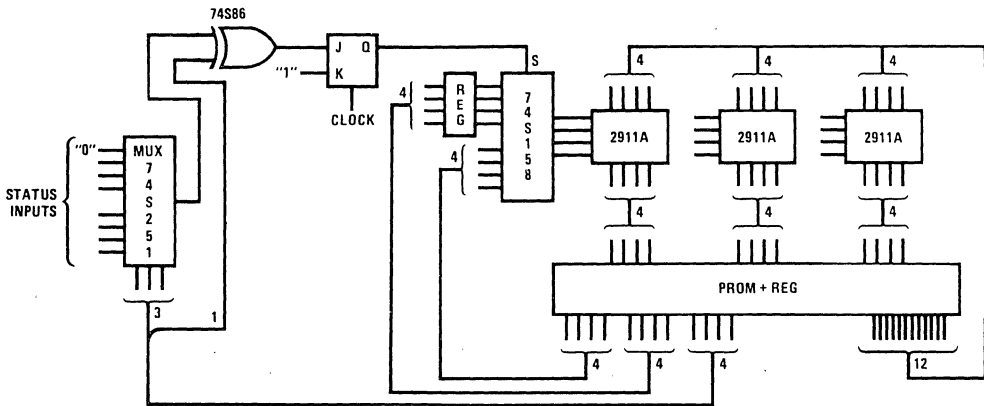
In less than two years, the 2900 bit-slice family has improved microcomputer speeds by 50% to 70%. The IDM2901A-1, the fastest part available, allows controlling and number-crunching CPU designs demanding less than 100ns per microcycle.

Faster microcontrol loops are required in order to take full advantage of ALU bit-slices like the IDM2901A and the IDM2901A-1.

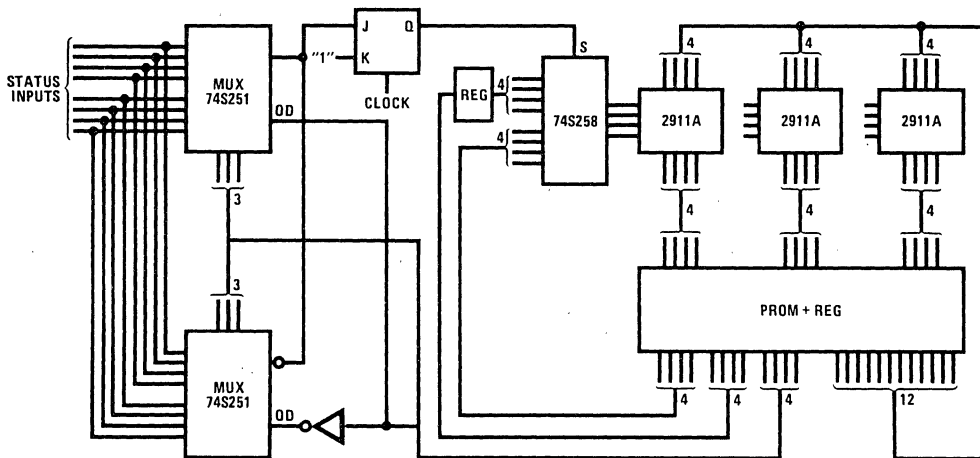
A few fast microcontrol loop designs have been explored, using the versatile IDM2909A/2911A microsequencer. These circuits are offered as basic suggestions, and as starting points for specific designs. Since, among other things, the data word width, the instruction repertoire and microstore size of a CPU will strongly influence the choice of which microcontrol loop design is best suited to yield the desired speed, price, microprogramming features, etc., the final choice must be made by the designer of a specific system.



Microcontroller, Circuit VI



Microcontroller, Circuit VII



Microcontroller, Circuit VIII

Fine Tuning the ALU Carry Path

National Semiconductor
Application Note 230
Harry Holt
May 1979



Most applications information for the IDM2902 Look-Ahead Carry Generator Family show three standard connections for 16-, 32-, and 64-bit Arithmetic Logic Units (ALUs). The three methods are shown in Figure 1.

With ALU cycle times in the 200 ns area, the standard connections shown in Figure 1 were quite adequate. A 5 to 10 ns overall savings did not warrant the time spent to examine alternative look-ahead carry

methods. However, with the introduction in 1978 of the IDM2901A-1, cycle times began to approach 100 ns. This was further reduced to less than 80 ns (for a 16-bit ALU) with the introduction of the IDM2901A-2 in 1979. Now, obviously, a 5 to 10 ns savings is significant and well worth a new look at look-ahead carry techniques. The purpose of this application note is to do just that and, as will be shown, some of the results do not favor the standard approaches.

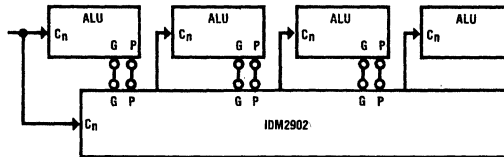


Figure 1(a). Conventional 16-Bit

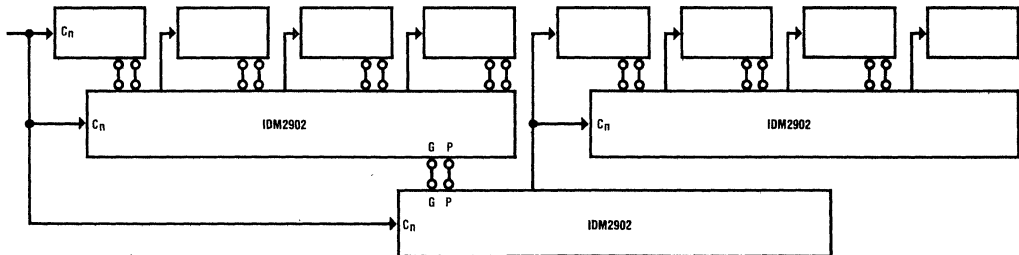


Figure 1(b). Conventional 32-Bit

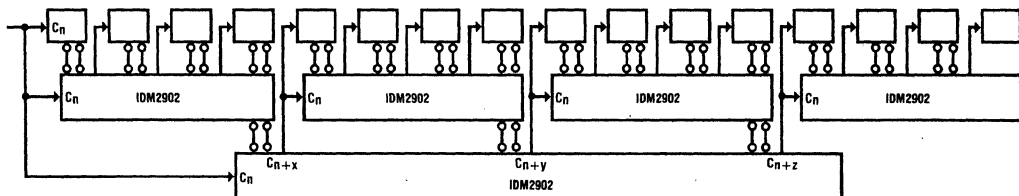


Figure 1(c). Conventional 64-Bit

BASIC METHODS

The basic methods examined in this application note can be divided into four categories:

1. Ripple Carry
2. Conventional Single Level
3. Multi-Level
4. Shifted

Ripple carry is generally considered to be slow, but at 8 bits it turns out to be the fastest method. Also, it will be shown that ripple carry can be used in combination with other methods to eliminate parts while adding very little to system cycle time. In most cases, the various methods will result in tradeoffs between parts count and system speed. It will be shown that some solutions, however, generate the highest performance with the fewest parts!

Single-level will be used to describe a system with a single layer of look-ahead carry even though technically this is a multi-level solution since the ALU itself looks across four bits. An example of a single-level approach is the 16-bit solution of Figure 1(a).

The conventional 32-bit connection [Figure 1(b)] is an example of multi-level look-ahead. In this approach, the carry-in is connected to two IDM2902s.

The least well known of the four methods is the shifted approach shown in Figure 2. Although this results in a slightly slower method in the 16-bit solution shown, there are word sizes where it can be the fastest method. Furthermore, freeing a set of G, P pins on the IDM2902 can have advantages in certain applications where sign-extension is required. (See Reference 1.)

As alluded to above, the various methods can be combined in a number of ways. The following is a list of the various combinations that were examined in this study. Almost all were applied to ALU sizes from 4 to 64 bits to identify the advantages and disadvantages of each. These will be summarized later.

Table I. Look-Ahead Carry Methods

1. Ripple
2. C_n
3. Shifted
4. Chained
5. Shifted Chain
6. Two Level
7. Two Level with Helpers
8. Shifted Two Level
9. Shifted Two Level with Helpers
10. Double Shifted Two Level
11. Double Shifted Two Level with Helpers
12. Three Level
13. Shifted Three Level
14. Double Shifted Three Level

FACTORS AFFECTING CHOICE

Before applying the look-ahead carry methods to the various word length ALUs, it may be worthwhile to look at some of the factors — other than raw speed — that could affect the choice of method. Some of these are:

1. parts count
2. board-to-board considerations
3. board space
4. sign extend
5. sequencer cycle time
6. board layout
7. word length expansion
8. different system architectures
9. current spiking

While parts count, board space, and board layout are more or less obvious considerations, the others deserve a brief comment:

- A. Board-to-board considerations refer to those systems where half of the ALU is on one board and half is on another. Obviously all methods would not be readily adaptable to this situation if a sufficient number of connector pins is not available.
- B. Sign-extend requirements may favor the method that frees a G,P input on one of the look-ahead carry circuits. This is explained more fully in Reference 1.
- C. Sequencer cycle time, in a pipelined system, may be the limiting factor in overall system speed. Thus, saving a few nanoseconds in the ALU may not be worthwhile.
- D. Future word length expansion is a consideration if several models of the same basic system are required. For example, 16 bits of address can address 64K words; twenty bits can address 1M words. If the ALU is used to compute addresses, the carry method optimized for 20 bits may be desirable.
- E. The architecture that was assumed for this study will not be used in every system. Thus, the availability and timing of input signals, worst-case delay paths, and added components will affect the results shown in the following section. Thus, each design could require a separate study to achieve optimized results.
- F. Current spiking is a consideration when one method causes several ALUs to change output states within a few nanoseconds of each other. If this causes system noise problems, perhaps an alternate method would be desirable.

APPLYING THE VARIOUS METHODS

In the following discussion, the IDM2901A-1 timing is used for the register-ALU elements. Because several different choices of pipeline register are available, the times shown do *not* include the clock-to-register output delay. Finally, the comparisons are based on the time required to add two registers and obtain a valid output, i.e., $A + B \rightarrow Y$.

4, 8 Bits: Ripple carry is clearly the best from all considerations and thus no further discussion is necessary. Register-to-register add time for 8 bits is 75 ns.

12 Bits: At present, the conventional single-level method is best (77 ns). However, if future bit-slices feature $A, B \rightarrow C_{n+4}$ as fast as $A, B \rightarrow \bar{G}, \bar{P}$ and $C_n \rightarrow C_{n+4}$ as fast as the IDM2902's $\bar{G}, \bar{P} \rightarrow C_{n+y}$, ripple carry can be just as fast. (This illustrates the need for designers to continually rethink the problem as new parts become available.)

16 Bits: Without considering sign extend, the conventional approach [Figure 1(a)] is optimum (75 ns). The shifted method (Figure 2) is 8.5 ns slower under the assumptions made above, but if sign extend is required,

Note: In the figures that follow, connecting lines are simplified and terminal labels are eliminated for clarity.

it may well be as fast, in addition to eliminating multiplexers. (See Reference 1.) (This illustrates the fact that two parts of a system optimized independently may result in an overall slower system.)

20 Bits: As word width increases above 16 bits, some of the less conventional approaches begin to have some advantage. First, consider the more obvious approaches; the single level and chained approaches are shown in Figures 3(a) and 3(b). Another solution can be obtained by deleting parts from the conventional 32-bit solution of Figure 1(b). This is shown in Figure 3(c).

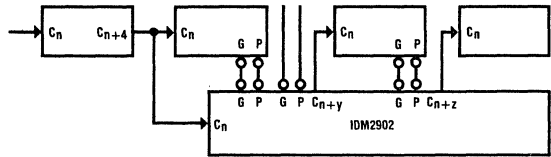


Figure 2. 16-Bit Shifted Look-Ahead

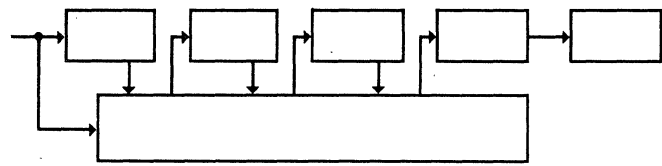


Figure 3(a). 20-Bit, Single-Level Method

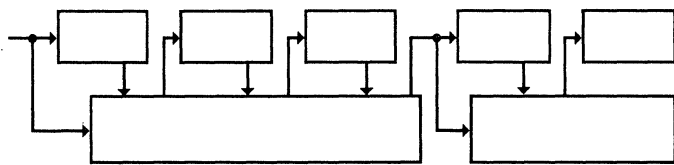


Figure 3(b). 20-Bit, Chained

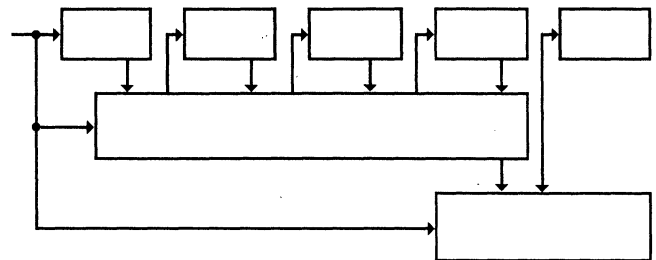


Figure 3(c). 20-Bit, Two-Level

From a timing standpoint, (b) and (c) of Figure 4 are both 87.5ns compared to 93ns for (a). The single-level method [Figure 3(a)] is superior from a parts count standpoint, requiring a single look-ahead carry rather than two. A closer look at Figure 3(c), however, reveals that only a small portion of the second look-ahead carry circuit is used. Furthermore, this portion can be replaced by a circuit consisting of 1/6 of a 74S04 and 1/2 of a 74S51 as shown in Figure 4. In addition to a lower power, lower cost solution, the replacement of the second look-ahead carry circuit actually saves 1.5ns!

Even more surprising is the fact that the shifted method shown in Figure 5 not only has the fewest parts, but also runs faster (85.5ns) than the other methods shown. Here is a situation where the speed-cost tradeoffs BOTH favor the same solution!

24, 28 Bits: Using the conventional 32-bit solution (deleting one or two ALUs) yields identical times (98 ns) for both 24 and 28 bits. The shifted chain (Figure 6), however, uses fewer parts and is faster (96 ns). With the same parts count, the chained and two-level methods yield the fastest times (87.5 ns) for both 24- and 28-bit ALUs.

32 Bits: The conventional approach for 32 bits shown in Figure 1(b) is an example of the two-level with helpers method. For 32 bits, the register-to-register add time is 98ns for this method. This is a faster approach than the chained and two-level methods (103.5ns) that were optimum for 24 and 28 bits. Another method — the

shifted two-level — again uses fewer parts and is considerably faster than the conventional approach (87.5 ns). This is illustrated in Figure 7.

36, 40, 44 Bits: A 98 ns solution can be obtained for 36-bit ALUs by simply deleting parts from the 64-bit solution of Figure 1(c). A word of caution: this is *not* the path to the most significant slice (MSS). It turns out that this path is only 87.5ns. The 98 ns path is to the output of the second MSS. The shifted two-level with helper method (Figure 8) will also produce a 98 ns result, but if the “helper” is replaced by the circuit of Figure 4, the result is 96.5 ns.

Another solution, requiring only two parts, is shown in Figure 9. This solution — the double shifted two-level method — turns out to be the best two-part solution for all word sizes from 36 to 64 bits. Speed for this method is 101.5 ns.

The shifted two-level with helper and double-shifted two-level methods turn out to be the optimum three-part and two-part solutions for 40- and 44-bit ALUs also.

48 Bits: As mentioned above, the double shifted two-level method shown in Figure 9 is also the optimum two-part solution for 48 bits. Three-part solutions are shown in Figure 10. The shifted three-level solution of Figure 10(a) results in a 114 ns system. The double shifted three-level solution is 101.5 ns. Note how the worst-case path varies between the two solutions. This points out the fact that several paths must be evaluated to ensure that the longest one has been found.

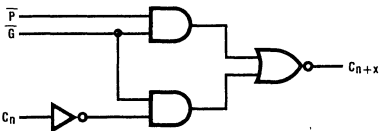


Figure 4. Partial Look-Ahead Carry Circuit

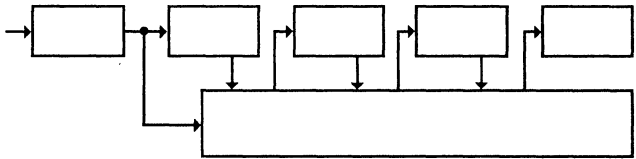


Figure 5. 20-Bit, Shifted

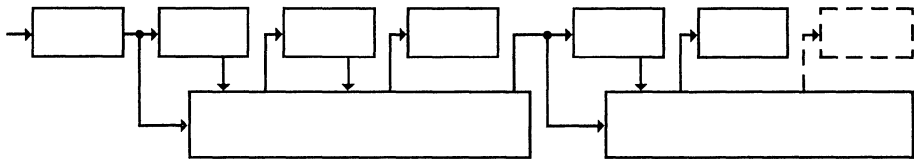


Figure 6. 24-, 28-Bit, Shifted Chain

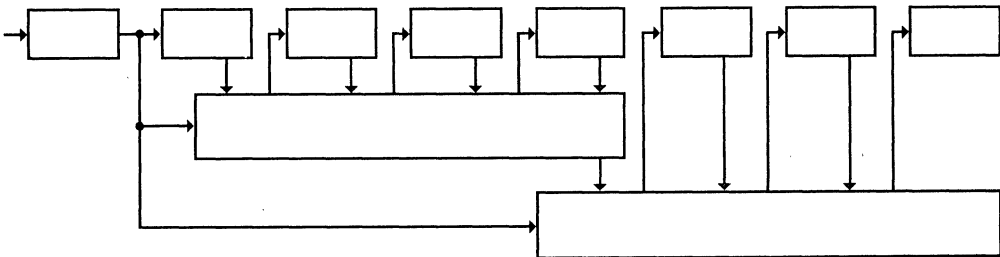


Figure 7. 32-Bit, Shifted Two-Level

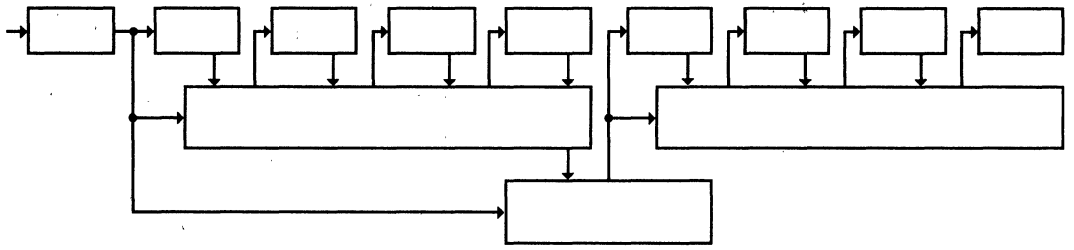


Figure 8. 36-Bit, Shifted Two-Level with Helper

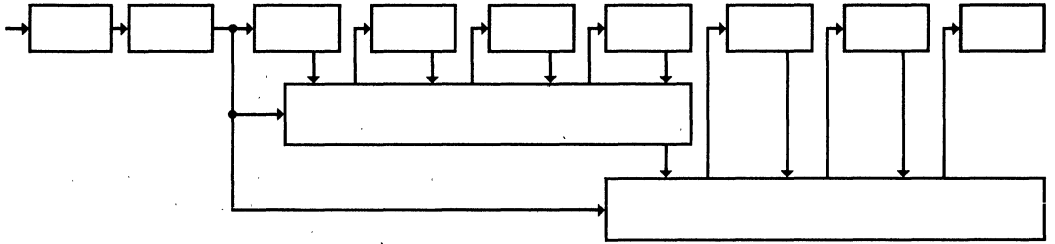


Figure 9. 36-Bit, Double-Shifted, Two-Level

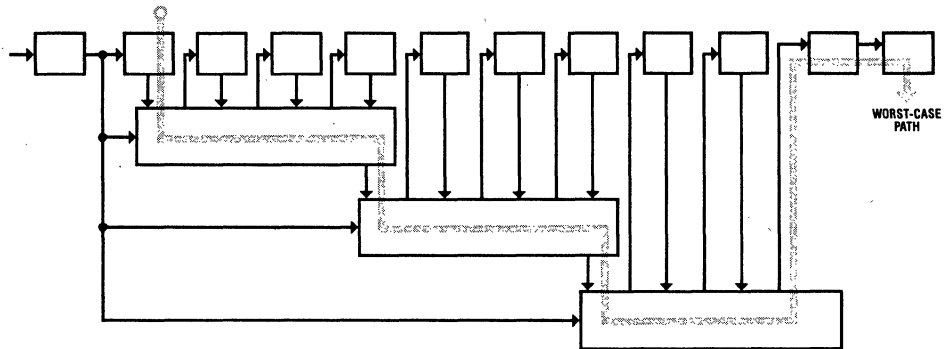


Figure 10(a). 48-Bit, Shifted, Three-Level

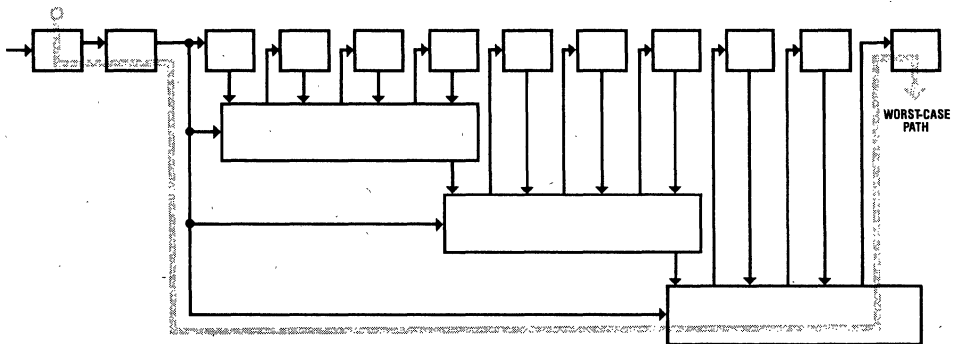


Figure 10(b). 48-Bit, Double Shifted, Three-Level

The four-part system of Figure 11 improves performance slightly (98ns) and may not be worth the additional expense. It is, however, the best four-part choice from 48 to 60 bits. This method is referred to as shifted two-level with helpers.

52 Bits: Not a particularly popular ALU size, the 52-bit system nevertheless provides an opportunity to demonstrate another look-ahead carry method — the double-shifted, two-level with helpers. This also turns out to be the fastest three-part method for word widths from 52 to 64 bits. This method, illustrated in Figure 12, results in 117.5ns for 52-bit systems.

56 Bits: ALUs of 56 bits are becoming common in floating point systems using 56 bits of mantissa and 8

bits of exponent. Deleting components from the conventional 64-bit approach [Figure 1(c)] results in a 98ns solution. This same speed, however, can be achieved with four parts using the shifted two-level with helper method of Figure 13.

60 Bits: The fastest 60-bit solution is the conventional approach for 64 bits [Figure 1(c)] with one alu deleted. This results in a 98ns solution. The shifted two-level with helper method (Figures 11 and 13) is a four-part solution that results in 103.5ns.

64 Bits: Again, the fastest 64-bit solution (98ns) is the conventional approach of Figure 1(c). The fastest four-part solution is a double-shifted two-level with helper method (117.5ns) illustrated in Figure 14.

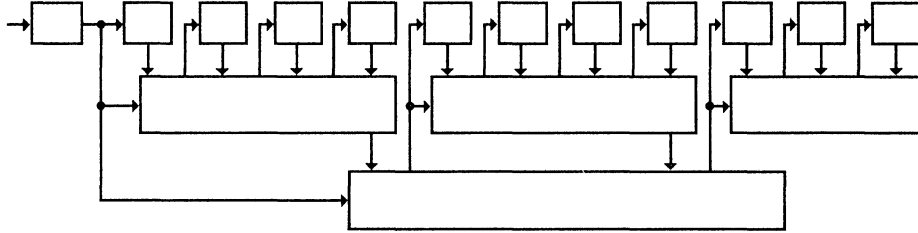


Figure 11. 48-Bit, Shifted Two-Level with Helpers

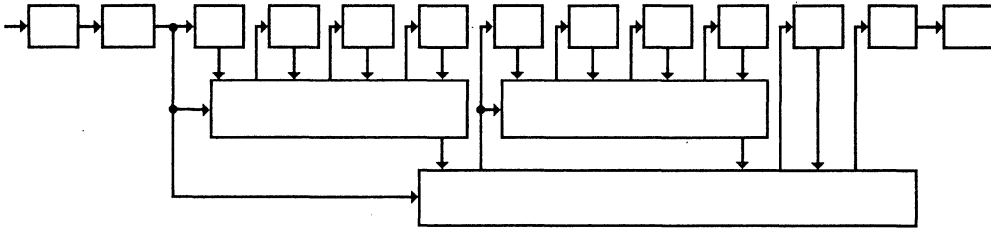


Figure 12. 52-Bit, Double-Shifted, Two-Level with Helpers

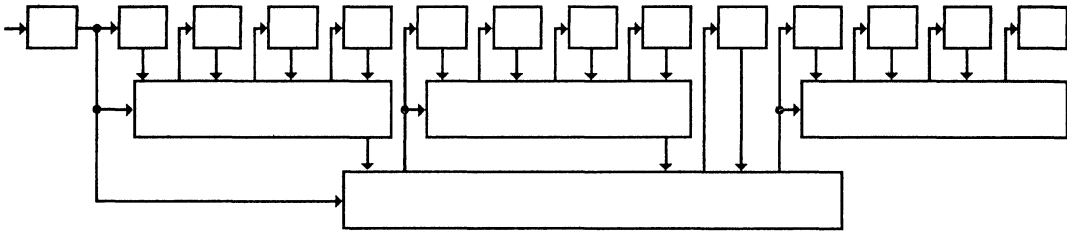


Figure 13. 56-Bit, Shifted, Two-Level with Helper

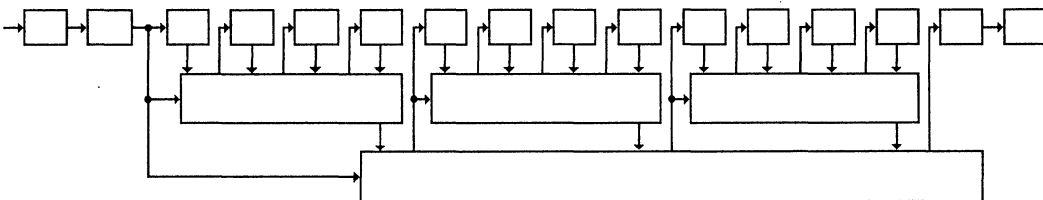


Figure 14. 64-Bit, Double Shifted, Two-Level with Helper

Table II is a summary of the data generated from this study. It lists, for each word size, the fastest solution for look-ahead carry parts count from 0 to 5. The number

under the "Method" column corresponds to the numbered list of Table I. The fastest solution for each word size is shaded.

Table II. Optimum Speed for 4-64-Bit ALUs

Word Size	Number of IDM2902s											
	0		1		2		3		4		5	
	Method	Time	Method	Time	Method	Time	Method	Time	Method	Time	Method	Time
4	1	50										
8	1	75										
12	1	91	2	77								
16	1	107	2	77								
20	1	123	3	85.5	4	87.5						
24	1	139	3	101.5	4, 6, 8	87.5	7	98				
28	1	155	3	117.5	4, 6, 8	87.5	9	98				
32	1	171	3	133.5	8	87.5	9	98				
36	1	187	3	149.5	10	101.5	7, 9, 12	98				
40	1	203	3	165.5	10	117.5	4, 7, 9, 12	98				
44	1	219	3	181.5	10	133.5	9, 13	98				
48	1	235	3	197.5	10	149.5	14	101.5	7, 9	98		
52	1	251	3	213.5	10	165.5	11	117.5	7, 9	98		
56	1	267	3	229.5	10	181.5	11	133.5	9, 13	98	7	98
60	1	283	3	245.5	10	197.5	11	149.5	9	103.5	7, 9	98
64	1	299	3	261.5	10	213.5	11	165.5	11	117.5	7, 9	98

CONCLUSIONS

It may appear that a lot of time was spent investigating alternate look-ahead carry schemes that save "a few nanoseconds" in overall speed. While this is certainly true for systems with ALU cycle times in the 200ns range, it has been shown that with the more recent 2900 components from National Semiconductor, ALU cycle times in the 100ns region are certainly feasible, and here those same few nanoseconds could become significant. This will be even more apparent with the introduction of the IDM2901A-2, which will improve the register/ALU times listed in Table III by another 20-25%.

It has also been shown that no one solution is "best" for all applications. Even the "fastest" solution may not be optimum for a specific system when parts count, system wiring, board space, etc., are considered.

Finally, the entire study will soon be obsolete as new components with different (albeit faster) specifications are introduced. Therefore, the only conclusion that seems legitimate is that each application should be considered individually with the requirements of the system, the devices available, and sound engineering judgement determining the optimum solution. It is hoped that the information contained in this application note will provide some guidelines for finding that solution.

REFERENCES

1. AN-203, Bit-Slice Microprocessor Design Takes a Giant Step Forward with "Schottky-Coupled-Logic" Circuits.
2. AN-217, High Speed Bit-Slice Microsequencing Design.

Table III. Delay Times Used to Calculate Cycle Time

IDM2901A-1:	IDM2902:
AB → Y 50ns	$\bar{G}, \bar{P} \rightarrow \bar{G}, \bar{P}$ 10.5ns
AB → \bar{G}, \bar{P} 45ns	$C_n \rightarrow C_{n+x,y,z}$ 10.5ns
AB → C_{n+4} 50ns	$\bar{G}, \bar{P} \rightarrow C_{n+x,y,z}$ 7.0ns
$C_n \rightarrow C_{n+4}$ 16ns	
$C_n \rightarrow Y$ 25ns	



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Introduction And General Description

What is a PAL?

A PAL is a user-programmable array of logic gates which allows the equivalent of a number of SSI and MSI (small- and medium-scale integration) packages to be implemented on a single chip. NSC's PAL series are Schottky TTL (transistor-transistor logic) components, and hence offer both speed and easy interfacing. Combinations of registers, flip-flops, and random logic are all easily implemented using PALs.

Why Should You Use A PAL?

Reduced board space

PALs typically implement the equivalent of from 4 to 12 SSI and MSI packages in a single 20-pin DIP. If the amount of space on your PCB is insufficient for your needs, you should seriously consider using PALs in your design.

Cost Effectiveness

The total manufacturing cost of a circuit implemented with PALs is frequently less than that of standard ICs. Only 25 to 50 per cent of the cost of utilizing an SSI or MSI chip is normally its purchase price; the remaining 50 to 75 per cent is tied up in the cost of the PCB area, assembly, and testing associated with that chip. Hence, as the PAL replaces more and more chips, its usage quickly becomes justified on a cost basis alone.

Fast System Design

Because of PALs' programmability and flexibility, the time needed to design and implement a system can be cut in half. Breadboards can be built quickly to test out new ideas without long waiting.

Design Flexibility

PALs offer the design engineer greater flexibility than standard, off-the-shelf parts. If a desired function is not readily available with standard components, an awkward assortment of chips may be needed to implement the function. With PALs, the engineer simply chooses what he wants instead of taking what he can get.

Easy Design Changes

PALs offer the designer the ability to reprogram an IC instead of redesigning other hardware and laying out a new PCB when the function of the card changes.

High Speed

PALs are built using Schottky technology. Register PALs clock at 40 MHz, with faster parts on the way.

Easy Field Programming

Unlike gate arrays and other approaches to custom logic design, the PAL is user-programmable, which minimizes turnaround time. The PAL can be programmed quickly and easily using standard PROM programmers with appropriate personality cards. Conversion of logic functions into the PAL format is accomplished quickly and easily using a software tool called PALASM™

Small Inventory

The PAL family can be used to replace up to 90 per cent of TTL components with just 15 different parts. This considerably lowers inventory costs.

What Is The Impact Of PAL On Logic Design?

Logic designers are noticing an apparent "complexity gap" between TTL and LSI. Products designed using discrete TTL devices would consume unacceptable amounts of physical space and electrical power. Software programmable LSI devices (microprocessors) offer high density and need relatively little power to do almost anything imaginable, but the designer pays a high price in software development and still has to use discretes to interface them to the outside world. Until recently, there has been no device that provides a really effective way of bridging this gap. National Semiconductor Company has seen this need, and now offers the designer a family of PAL (Programmable Array Logic) devices to fill it. PALs offer powerful capabilities for

creating cost-effective new products or for improving the effectiveness of existing logic designs. PAL devices save time and money by solving many of the system partitioning and interface problems not otherwise effectively solved by today's semiconductor device technology.

LSI (Large scale integration) offers many advantages, but advances have been made at the expense of either device flexibility or software complexity. LSI technology has been and still is leading to larger and larger standard logic functions. LSI offers high functional density and low power consumption; single ICs now perform functions that formerly required complete circuit cards. However, most LSI devices don't interface with user systems without large numbers of support devices. Designers are still forced to turn to random logic for many applications. LSI is slow, and it is rigidly partitioned. For all its capability to perform varied and complex tasks, the microprocessor is a slow and expensive way of doing simple, repetitive tasks when the necessary interface and other support devices are added, and when the time, money, and memory required for software development are considered.

TTL provides speed, and you could say its flexibility is infinite, but its price is high power consumption, large parts count, and low space utilization.

Custom IC's can be effective design solutions if the product is of low-to-medium complexity, its logic function is well defined, and its market is high volume. Its design cycle is typically long, and its cost can be prohibitive. This tends to discourage its use.

Fuse-programmable devices of various kinds have been invented to try to overcome the above-mentioned disadvantages. All but PAL require external interface logic, and all but PAL have disadvantages, to wit:

PROM: Requires careful design to avoid undesirable data transitions. Also limited on the number of input variables it can accommodate.

FPLA: Is expensive, difficult to program, and hard to understand.

FPGA: Isn't widely available, and lacks flexibility.

PMUX: Is available in only a few types.

The PAL—A New Extension of Fusible-Link Technology

The diode matrix was the first programmable integrated-circuit logic device, introduced in

the early 1960's. This device contained only a diode-logic OR matrix, each crosspoint of which had a fusible link.

The programmable read-only memory (PROM) extended the programmable logic concept considerably by allowing input variables to be encoded, by reducing the number of pins required per input variable, and by providing TTL compatibility. The PROM is an AND-OR logic element with fixed AND matrix and programmable OR.

One advantage of using PROMS is that they are produced in high volume because they are used in many applications. Also, the PROM is a universal logic solution; in other words, all the product terms of the input variables are generated, making it possible to implement any AND-OR function of these variables.

The Field-Programmable Logic Array (FPLA) has a second fuse matrix (an AND matrix), so allows the designer to select and program only those product terms used in each specific function. These product terms are then combined in the OR fuse array to form an AND-OR logic equation. More about these later.

How It Works (See Figure 1-1.)

In the PAL concept, an AND fuse array allows the designer to specify the product terms required, and connect them to an OR matrix chosen to perform the required combination of AND-OR logic functions. PALs are offered in a number of different part types that vary the OR-gate configuration. Specifying the OR-gate connection therefore becomes a task of device selection rather than of programming, as with the FPLA. With this approach, PALs eliminate the need for a second fuse matrix with little loss in overall flexibility. Figure 1 is a schematic diagram that shows how a typical PAL circuit processes a two-input, one-output logic segment. The general logic equation for this segment is:

$$\text{Output} = (I_1 \cdot f_1 + /f_1) (/I_1 \cdot f_2 + /f_2) (I_2 \cdot f_3 + /f_3) (/I_2 \cdot f_4 + /f_4) + (I_1 \cdot f_5 + /f_5) (/I_1 \cdot f_6 + /f_6) (I_2 \cdot f_7 + /f_7 + /f_7) (I_2 \cdot f_8 + /f_8)$$

where the "f" terms represent the states of the fuse links in the PAL's AND array. In the above equation, an intact fuse is represented by $f = 1$, and a blown fuse by $f = 0$.

Although logic equations are convenient for simple functions, they become progressively less tractable as the functions become more complex. In large systems, the logic diagram, or schematic, and the truth table are the methods more commonly used to describe

logic networks. For simplicity, PAL logic is described in this book using the symbolic notation shown at right in Figure 1-2. The conventional, combinational logic diagram of the same expression is shown at left. In the figure, an X represents an intact fuse which, in conjunction with the series diode (not shown schematically), performs the logical AND function.

The two-input, one-output example shown in Figure 1-1, redrawn using the new logic notation, is depicted in Figure 1-3.

Figure 1-4 is the normal combinational logic diagram of an example whose transfer function is as follows:

$$\text{Output} = I_1 \cdot \bar{I}_2 + \bar{I}_1 \cdot I_2$$

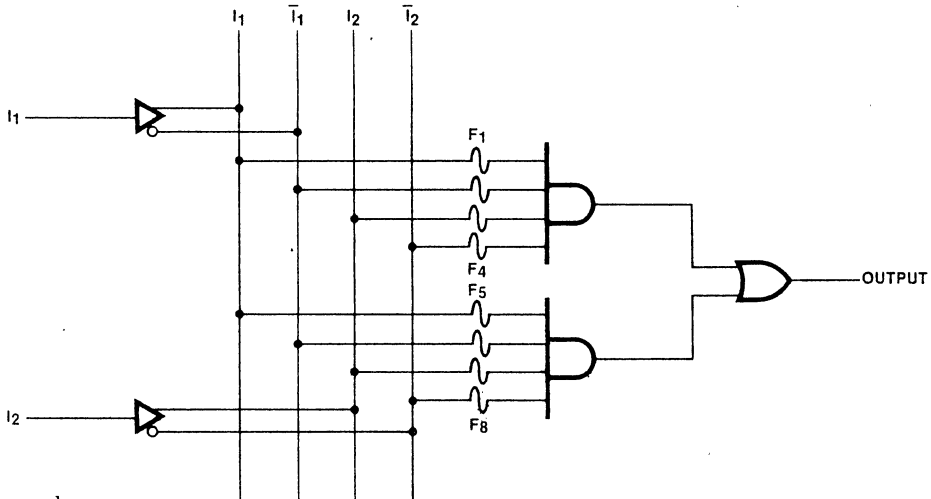


FIGURE 1-1. Partial Logic Diagram of a PAL®

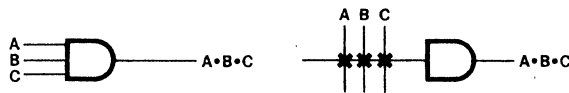


FIGURE 1-2. Conventional and PAL Logic Notation.

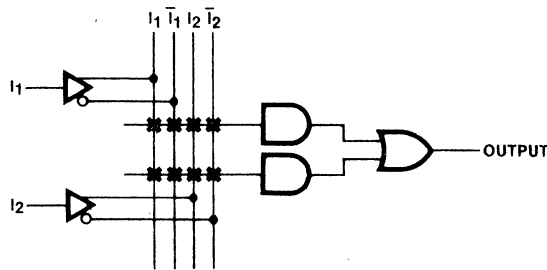


FIGURE 1-3. Two-input, One-output PAL Circuit, Unprogrammed.

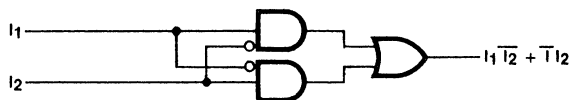


FIGURE 1-4. Logic Diagram of the Expression Shown Above

As can be seen from the expression and diagram, this is a two-input, one-output circuit; hence, the circuit of Figure 1-3 appears to be a good candidate to solve this problem. Removing the Xs from the junctions that do not represent terms of the example Boolean expression results in the diagram shown in Figure 1-5, which is the same PAL circuit shown in Figure 1-3, except that the appropriate fuses are blown.

Using the symbology described here not only displays the attributes of a logic diagram, but also those of the truth table for the same expression diagrammed. With this technique, it is possible to compare the structure of the PAL with those of the familiar PROM and PLA.

Comparison

To illustrate the differences among the three field-programmable logic concepts, each of the approaches is shown as an AND matrix, followed by an OR matrix. The basic logic implemented by the PROM is AND-OR, with the AND gates all preconnected on the chip, making this portion fixed, while the OR matrix is implemented with diode-fuse interconnections, making it programmable. Thus, the PROM is an AND-OR logic element with fixed AND matrix and programmable OR. The PROM solution in Figure 1-6 requires a 64-fuse matrix. There are many advantages to using PROMs as logic devices. One is that because they are used in many applications, they are produced in high volume. Also, the PROM is a universal logic solution; in other words, all the product terms of the input variables are generated, making it possible to implement any AND-OR function of these variables. However, PROMs cannot accommodate large numbers of variables; the maximum number of input variables currently being realized is 11.

The Field-Programmable Logic Array (FPLA) has a second fuse matrix (an AND matrix), allowing the designer to select and program only those product terms used in each specific function. (See Figure 1-7.) These product terms are then combined in the OR fuse array to form an AND-OR logic equation.

The typical FPLA implementation has less than 2^n terms available (with n as the number of input variables). This allows the FPLA to accommodate larger values of n , i.e., more inputs, in contrast with the PROM, where the number of product terms is always equal to 2^n . Although the FPLA usually requires fewer fuses to implement a given logic function, additional circuitry is required to select and program these fuses—circuitry that is not used in the final logic solution, but which is paid for in die area. This “chip overhead” cost becomes significant for simple applications that leave logic unused.

The basic logic structure of the PAL, consisting of a programmable AND array whose outputs feed a fixed OR array, is shown in Figure 1-8. The PAL is low in cost and easy to program, like the PROM, but also is more flexible, like the FPLA. Table 1-1 lists the characteristics of the three principal families of devices described here, and also others, for comparison.

Table 1-1.
Programmable Logic Device Summary

Device	AND	OR	Output Options
PROM	Fixed	Prog	TS,OC
FPLA	Prog	Prog	TS,OC,Fusable Polarity
FPGA	Prog	None	TS,OC,Fusable Polarity
PMUX	Fix/Prog	Fixed	TS
PAL	Prog	Fixed	TS,Registers,Feedback,I/O

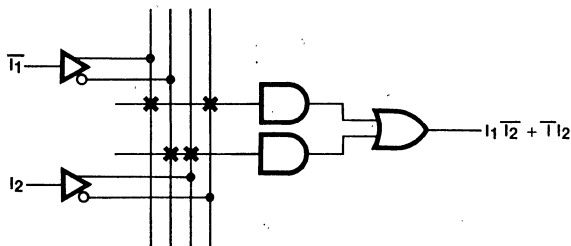


FIGURE 1-5. Blown Junctions Make the PAL Useful.

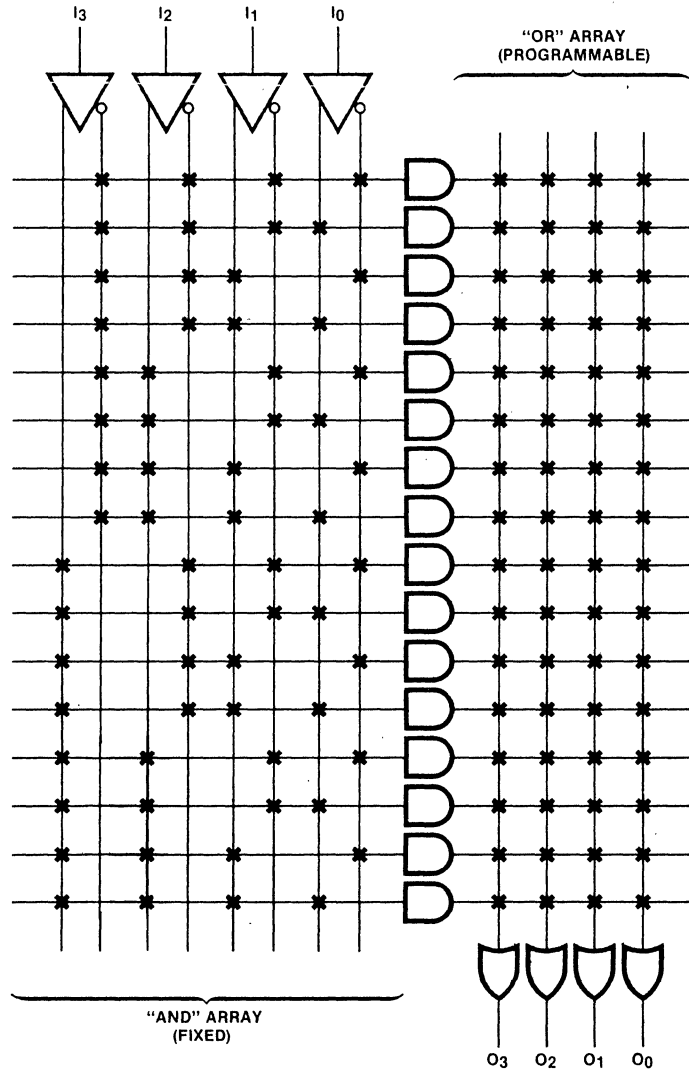


FIGURE 1-6. PROM Having 16 Words x 4 Bits.

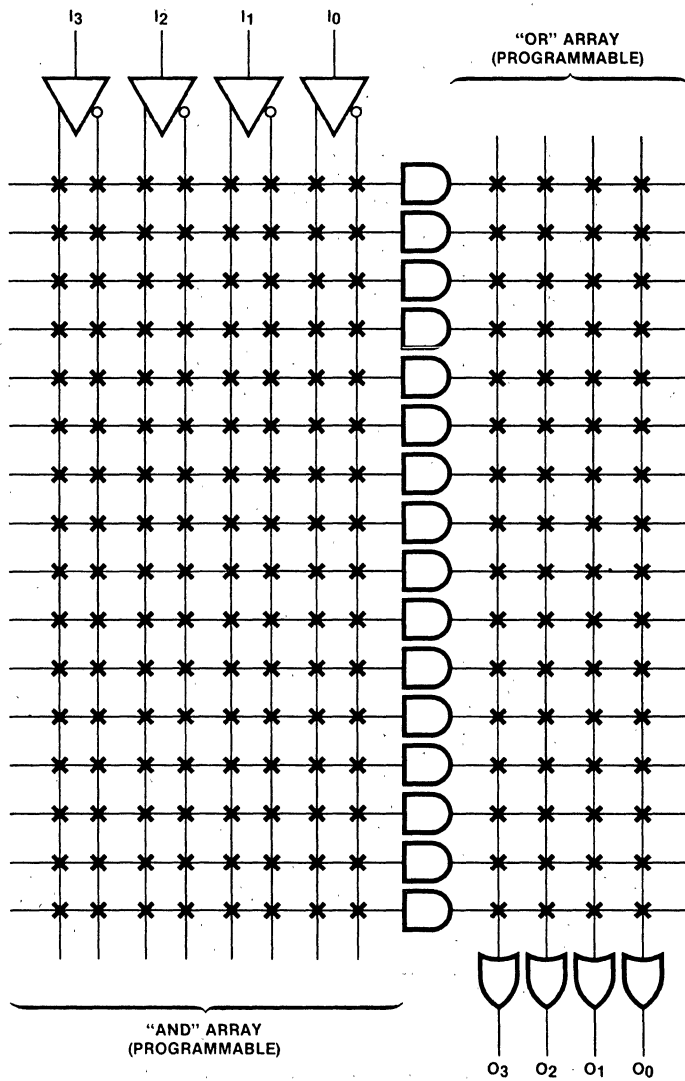


FIGURE 1-7. FPLA Having 4 Inputs, 4 Outputs, and 16 Products.

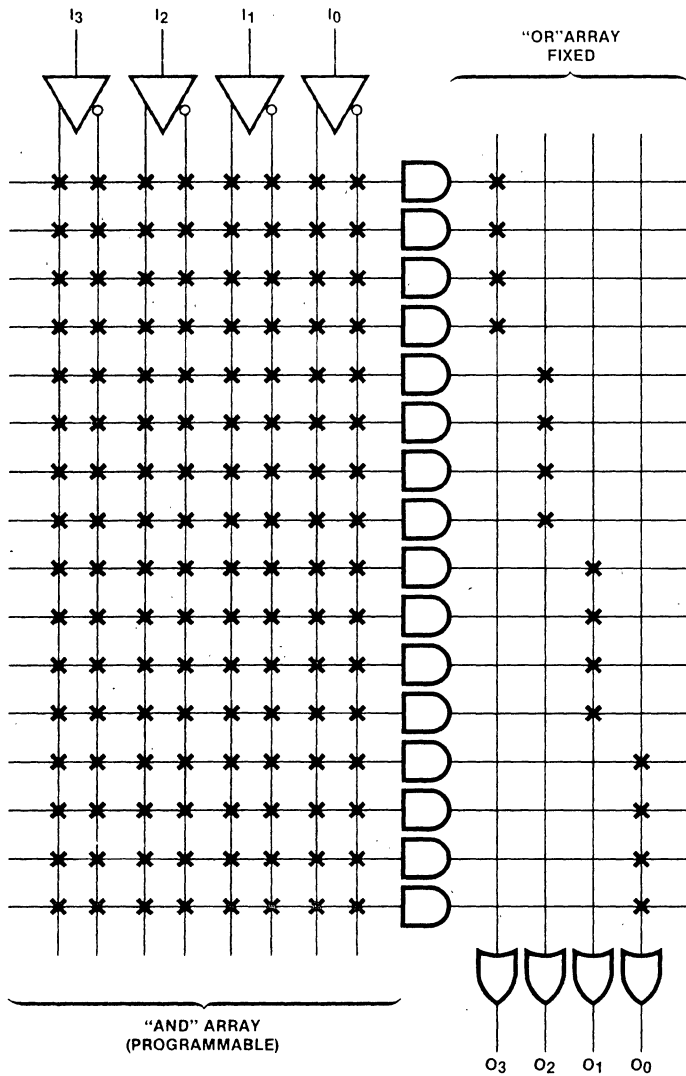


FIGURE 1-8. PAL Having 4 Inputs, 4 Outputs, and 16 Products.

TABLE 1-2. THE PROGRAMMABLE ARRAY LOGIC (PAL®) FAMILY

Std (35 ns)	High Speed (25 ns)	Pkg Pin	Description
10H8	10H8A	20	10 input, 8 output AND-OR array
12H6	12H6A	20	12 input, 6 output AND-OR array
14H4	14H4A	20	14 input, 4 output AND-OR array
16H2	16H2A	20	16 input, 2 output AND-OR array
10L8	10L8A	20	10 input, 8 output AND-OR array
12L6	12L6A	20	12 input, 6 output AND-OR array
14L4	14L4A	20	14 input, 4 output AND-OR array
16L2	16L2A	20	16 input, 2 output AND-OR array
16C1	16C1A	20	16 input, 1 output AND-OR/NOR array
16L8	16L8A	20	16 input, 8 output AND-OR-invert array
16R8	16R8A	20	16 input, 8 output AND-OR-register array
16R6	16R6A	20	16 input, 6 output AND-OR-register array
16R4	16R4A	20	16 input, 4 output AND-OR-register array
16X4		20	16 input, 4 output AND-OR-XOR-register array
16A4		20	16 input, 4 output AND-CARRY-OR-XOR register
12L10		24	12 input, 10 output AND-OR invert array
14L8		24	14 input, 8 output AND-OR-invert array
16L6		24	16 input, 6 output AND-OR-invert array
18L4		24	18 input, 4 output AND-OR-invert array
20L2		24	20 input, 2 output AND-OR-invert array
20C1		24	20 input, 1 output AND-OR/NOR array
20L10		24	20 input, 10 output AND-OR-invert array
20X10		24	20 input, 10 output AND-OR-XOR-register array
20X8		24	20 input, 8 output AND-OR-XOR-register array
20X4		24	20 input, 4 output AND-OR-XOR-register array

PALs For Every Task

The members of the PAL family are listed in Table 1-2. They are designed to cover the spectrum of logic functions at lower cost and lower package count. This allows you to select the PAL that best fits your application. PALs come in four basic configurations:

- Gates
- Register Outputs With Feedback
- Programmable I/O
- Arithmetic Functions

Gates

For 20/20A series, PALs are available in sizes from 10×8 (10 inputs 8 outputs) to 16×2 , with either active-high or active-low output configurations. For 24 series, PALs are available in sizes from 12×10 to 20×2 with active-low output configurations. One part has complementary outputs with both series. This wide variety of input/output formats allows the PAL to replace many different-sized blocks of combinational logic with single packages.

Register Outputs With Feedback

High-end members of the PAL family feature latched data outputs with register feedback. Each sum or product term is stored in a D flip-flop on the rising edge of the system clock. (See Figure 1-9.) The Q output of the flip-flop can then be gated to the output pin by enabling the active-low TRI-STATE® buffer.

In addition to being available for transmission, the Q output is also fed back into the PAL array as an input term. This feedback allows the PAL to "remember" its prior state, and it can alter its function based upon that state. This allows you to configure the PAL as a state machine that can be programmed to execute elementary functions such as count up, count down, skip, shift, and branch.

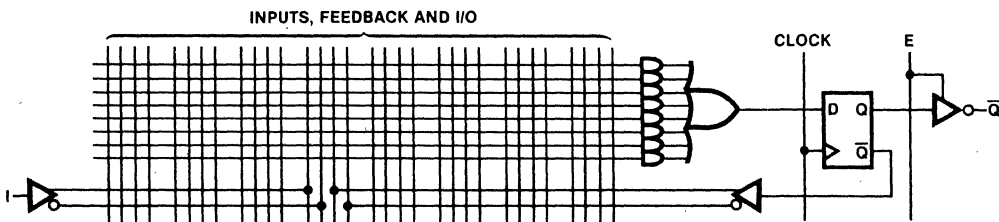


FIGURE 1-9. PAL Output Register Circuit, Simplified Logic Diagram.

Programmable I/O

Another feature of the high-end members of the PAL family is programmable input/output. This allows the product terms to directly control the outputs of the PAL. (See Figure 1-10.) One product term is used to enable the TRISTATE[®] buffer, which in turn gates the summation term to the output pin. The output is also fed back into the PAL array as an input. Thus, the PAL drives the I/O pin when the TRISTATE[®] gate is enabled; the I/O pin is an input to the PAL array when the TRISTATE[®] gate is disabled. This feature can be used to allocate available pins for I/O functions or to provide bidirectional output pins for operations such as shifting and rotating serial data.

Arithmetic Functions

The arithmetic functions add, subtract, greater than, and less than are implemented by two additional features of the register PAL. (See Figure 1-11.) First, the sums that are XORed at the input of a D flip-flop. This allows carries from previous operations to be XORed with current sums generated by the PAL array. Second, the Q output of the flip-flop is ORed with an input to form the terms $I + Q$, $I + /Q$, $I + Q$, and $I + /Q$, which are then fed back into the PAL matrix. This option provides for versatile operations on two variables and facilitates the parallel generation of carries necessary for fast arithmetic operations. Figure 1-12 shows a PAL array, programmed to combine the available terms to form 16 logical products in an ALU or controller application.

Technology

National Semiconductor PALs are manufactured using the same high-volume technology used in the manufacture of PROMs. This includes state-of-the-art Schottky processing, dual-layer metal, and highly reliable titanium-tungsten fuses. NPN emitter followers make up the programmable AND array. The inputs are PNP transistors whose input impedance imposes a current drain of not more than 0.25 mA on the source. All outputs are standard TTL drivers with internal active-pullup transistors. Typical PAL propagation delay is 25 ns for the standard version.

Packaging

All PAL versions are supplied in the space-saving 20 and 24-pin, 0.3-in. "thin-dip" package. This package offers one of the best pin-count-to-area ratios available.

PALS also utilize National's copper-lead-frame plastic package design that combines the low cost of plastic with the thermal characteristics of CERDIP to provide highly reliable, cost-effective components.

Programming PALs are designed to be programmed using standard, commercially available PROM programmers with the addition of the proper personality module and socket adapters. Some programmers with PAL programming capability are listed in the PAL Design section.

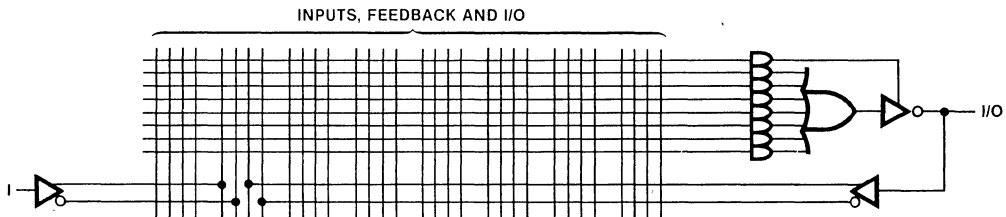


FIGURE 1-10. PAL Bidirectional Circuit, Logic Diagram.

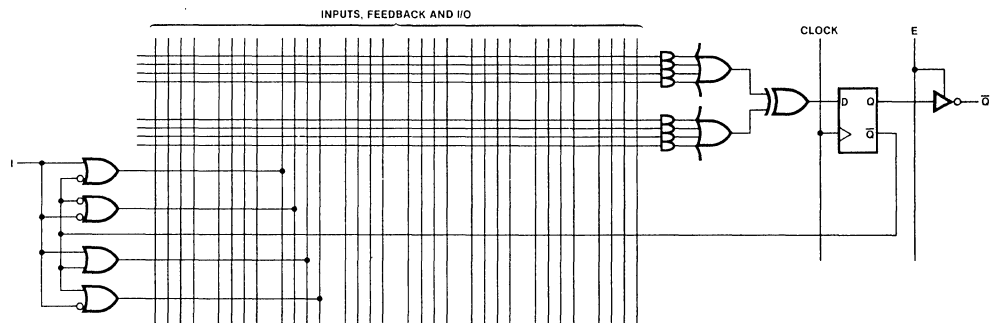


FIGURE 1-11. Logic Structure of an Arithmetic PAL.

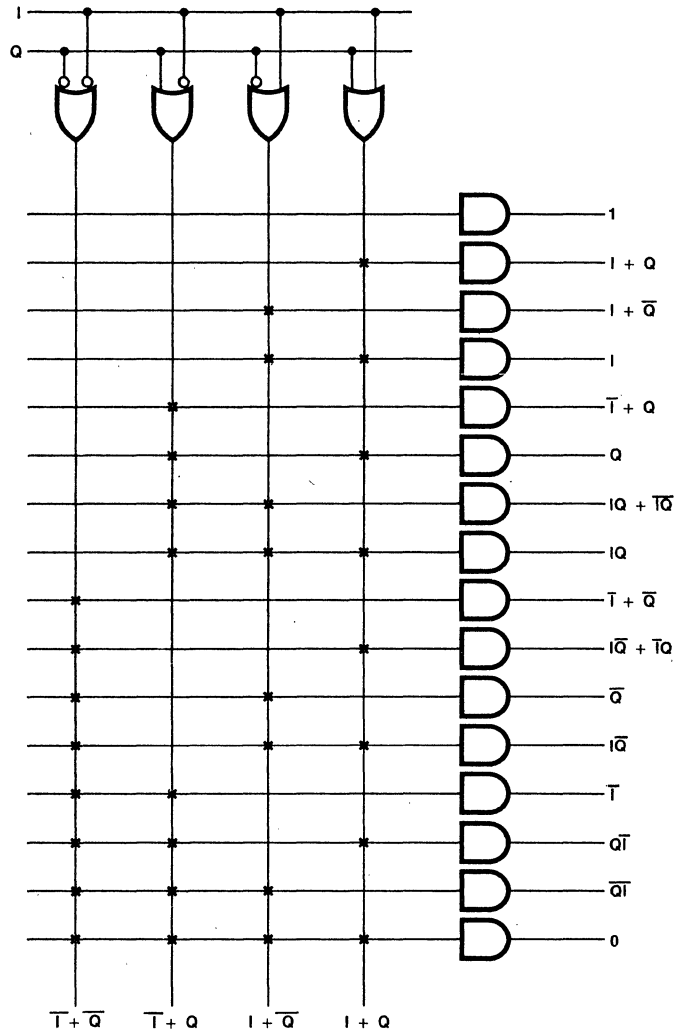


FIGURE 1-12. PAL Coding to Perform Typical ALU Functions.

PAL Part Numbers

The PAL part number reveals the logic operation the part performs. (See Figure 1-13.) The example shown, the DMPAL16L2NC, is a device that accommodates 16 input terms and

generates 2 active-low output terms, is contained in a 20-pin plastic dual-inline package, and meets commercial temperature-range specifications.

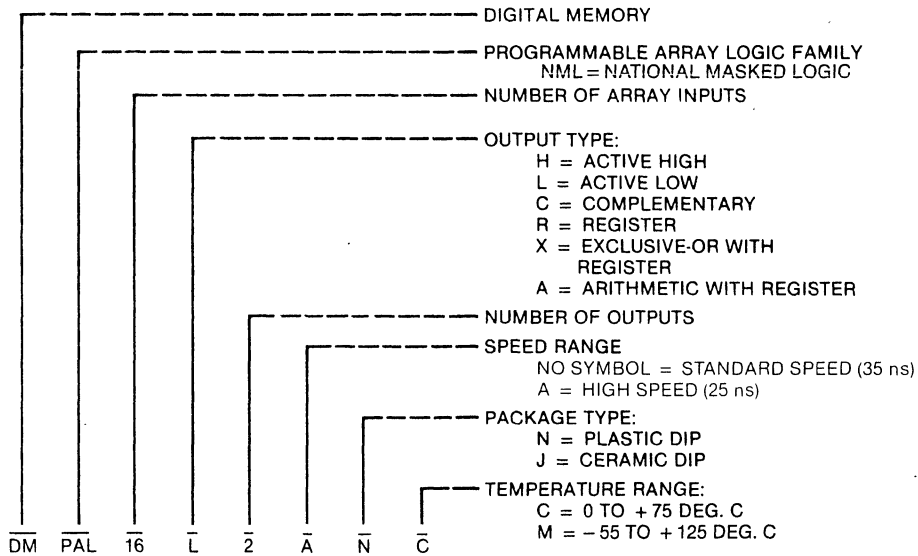


FIGURE 1-13. Meaning of PAL Part Number Code

PAL Logic Symbols

The logic symbols for each of the individual PAL devices gives a concise functional description of that device. Figure 1-14 shows a typical logic symbol, that of the 10H8 gate array.

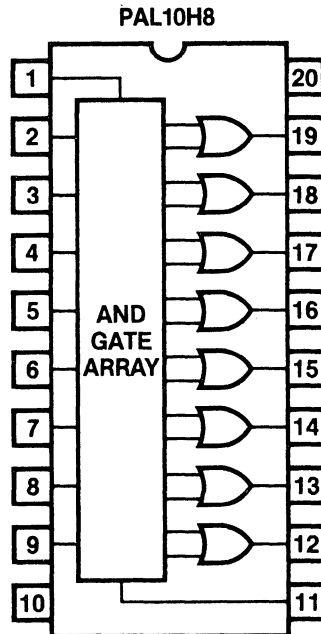
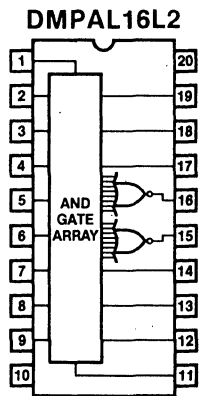
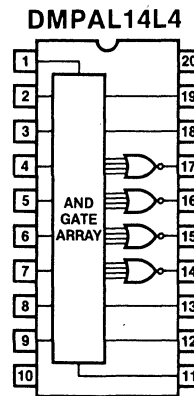
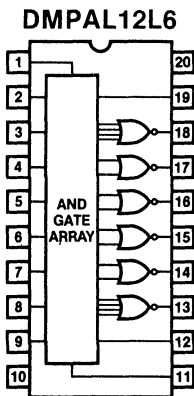
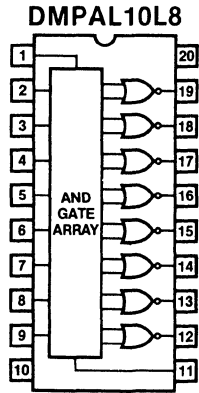
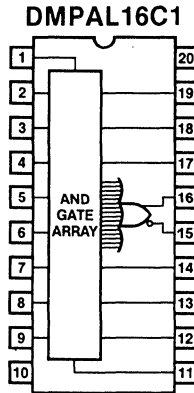
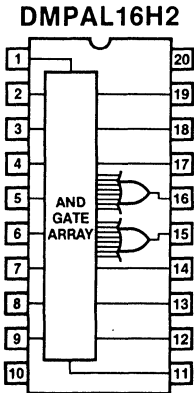
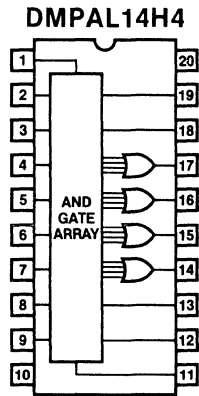
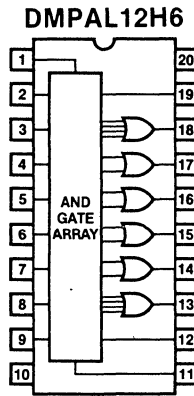
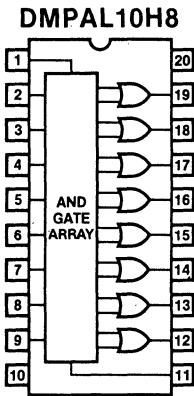
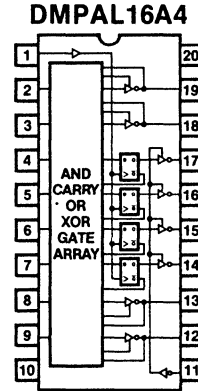
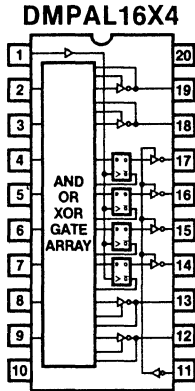
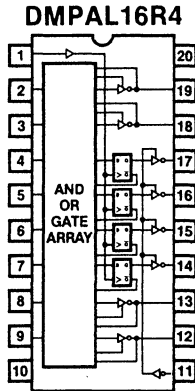
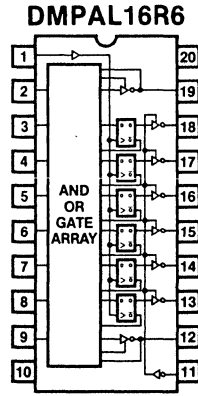
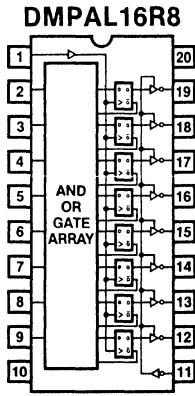
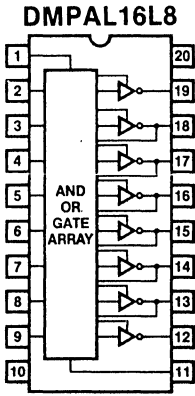


FIGURE 1-14. Logic Symbol, DMPAL10H8.

PAL Logic Symbols — Series 20

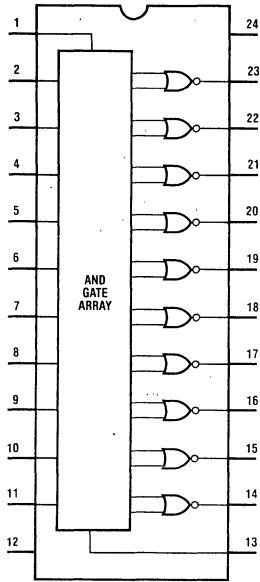


PAL Logic Symbols - Series 20 (Contd.)

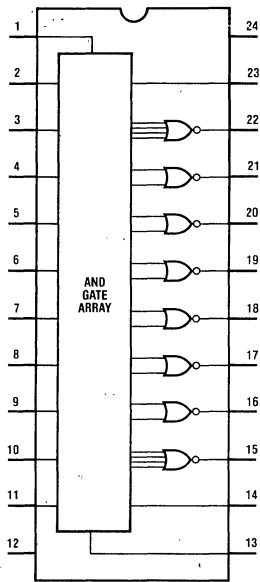


PAL Logic Symbols - Series 24

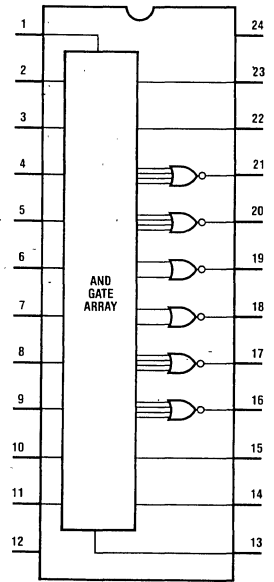
PAL12L10



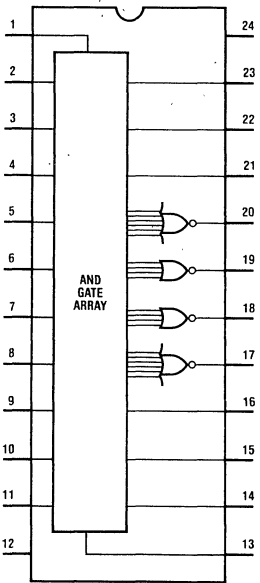
PAL14L8



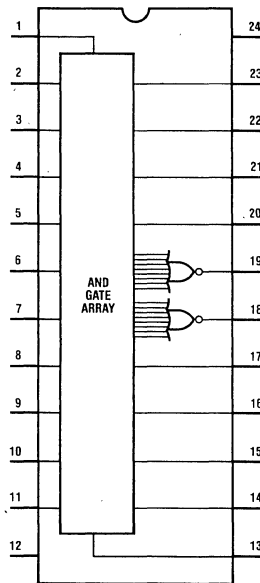
PAL16L6



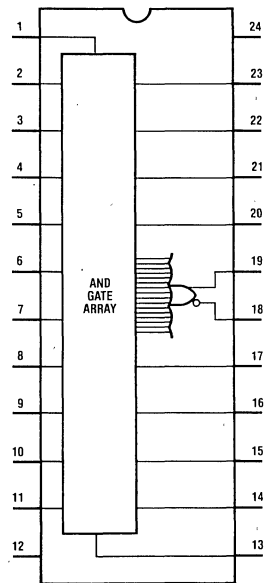
PAL18L4



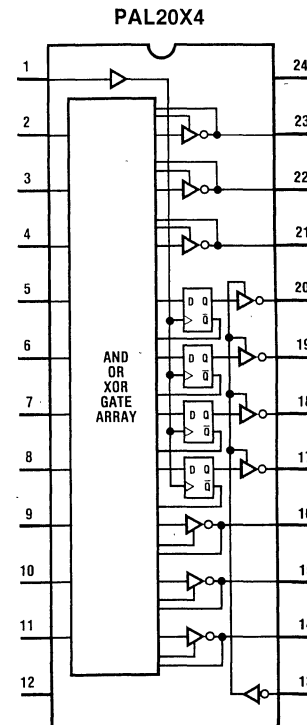
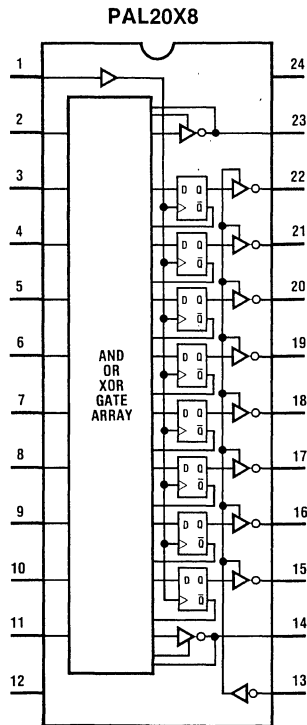
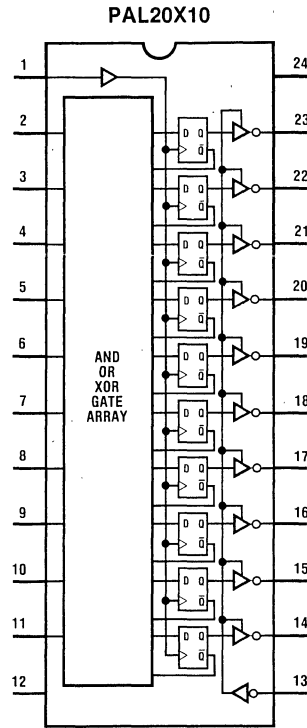
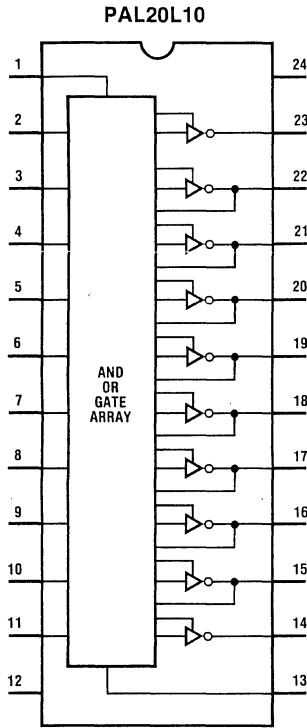
PAL20L2



PAL20C1



PAL Logic Symbols - Series 24 (Contd.)





DATA SHEETS

Programmable Array Logic (PAL[®]) Series 20/20A

Description

The PAL[®] family utilizes National Semiconductor's Schottky TTL process and bipolar PROM fusible-link technology to provide user-programmable logic to replace conventional SSI/MSI gates and flip-flops. Typical chip count reduction gained by using PALs is greater than 4:1.

The family lets the systems engineer customize his chip by opening fusible links to configure AND and OR gates to perform his desired logic functions. Complex interconnections that previously required time-consuming layout are thus transferred from PC board to silicon where they can be easily modified during prototype checkout or production.

The PAL transfer function is the familiar sum of products with a single array of fusible links. Unlike the PROM, the PAL is a programmable AND array driving a fixed OR array. (The PROM is a fixed AND array driving a programmable OR array.) In addition, the PAL family offers these options:

- Variable input/output in ratio.
- Programmable TRISTATE[®] outputs.
- Registers and feedback.

Unused inputs are tied directly to V_{CC} or GND. Product terms with all fuses blown assume the logical high state, and product terms connected to both true and complement of any single input assume the logical low state. Registers consist of D type flip-flops that are loaded on the low-to-high transition of the clock. PAL logic diagrams are shown with all fuses blown, enabling the designer to use the diagrams as coding sheets.

The entire PAL family is programmed on conventional PROM programmers with appropriate personality and socket adapter cards. Once the PAL is programmed and verified, two additional fuses may be blown to make verification difficult. This feature gives the user a proprietary circuit that is very difficult to copy.

Features

- Programmable replacement for conventional TTL logic.
- Simplifies prototyping and board layout.
- Thin DIP packages.
- Reliable titanium-tungsten fuses.
- Available in standard and high speed versions.
- 25 ns max propagation delay for high speed versions (20A series)

Table 2-1. Part Types

Part Number	Description
PAL10H8	OCTAL 10 INPUT AND-OR GATE ARRAY
PAL 12H6	HEX 12 INPUT AND-OR GATE ARRAY
PAL 14H4	QUAD 14 INPUT AND-OR GATE ARRAY
PAL 16H2	DUAL 16 INPUT AND-OR GATE ARRAY
PAL 16C1	16 INPUT AND-OR/AND-OR-INVERT GATE ARRAY
PAL 10L8	OCTAL 10 INPUT AND-OR-INVERT GATE ARRAY
PAL 12L6	HEX 12 INPUT AND-OR-INVERT GATE ARRAY
PAL 14L4	QUAD 14 INPUT AND-OR-INVERT GATE ARRAY
PAL 16L2	DUAL 16 INPUT AND-OR-INVERT GATE ARRAY
PAL 16L8	OCTAL 16 INPUT AND-OR-INVERT GATE ARRAY
PAL 16R8	OCTAL 16 INPUT REGISTERED AND-OR GATE ARRAY
PAL 16R6	HEX 16 INPUT REGISTERED AND-OR GATE ARRAY
PAL 16R4	QUAD 16 INPUT REGISTERED AND-OR GATE ARRAY
PAL 16X4	QUAD 16 INPUT REGISTERED AND-OR-XOR GATE ARRAY
PAL 16A4	QUAD 16 INPUT REGISTERED AND-CARRY-OR-XOR GATE ARRAY

Part Number	Description
PAL10H8A	OCTAL 10 INPUT AND-OR GATE ARRAY
PAL12H6A	HEX 12 INPUT AND-OR GATE ARRAY
PAL14H4A	QUAD 14 INPUT AND-OR GATE ARRAY
PAL16H2A	DUAL 16 INPUT AND-OR GATE ARRAY
PAL16C1A	16 INPUT AND-OR/AND-OR-INVERT GATE ARRAY
PAL10L8A	OCTAL 10 INPUT AND-OR INVERT GATE ARRAY
PAL12L6A	HEX 12 INPUT AND-OR-INVERT GATE ARRAY
PAL14L4A	QUAD 14 INPUT AND-OR-INVERT GATE ARRAY
PAL16L2A	DUAL 16 INPUT AND-OR-INVERT GATE ARRAY
PAL16L8A	OCTAL 16 INPUT AND-OR-INVERT GATE ARRAY
PAL16R8A	OCTAL 16 INPUT REGISTERED AND-OR GATE ARRAY
PAL16R6A	HEX 16 INPUT REGISTERED AND-OR GATE ARRAY
PAL16R4A	QUAD 16 INPUT REGISTERED AND-OR GATE ARRAY

Absolute Maximum Ratings

	Operating	Programming
Supply voltage V_{CC}	7.0 V	12 V
Input voltage	5.5 V	12 V
Off-state output voltage	5.5 V	12 V
Storage temperature range	-65°C	to 150°C

10H8, 12H6, 14H4, 16H2, 16C1, 10L8, 12L6, 14L4, 16L2

Electrical Characteristics

Over Recommended Operating Temperature Range

Symbol	Parameter	Test Conditions	Operating			Unit
			Min	Typ	Max	
V_{IH}	High-level input voltage		2			V
V_{IL}	Low-level input voltage				0.8	V
V_{IC}	Input clamp voltage	$V_{CC} = \text{MIN}$ $I_I = -18 \text{ mA}$			-1.5	V
V_{OH}	High-level output voltage	$V_{CC} = \text{MIN}$ $V_{IH} = 2\text{V}$ $V_{IL} = 0.8\text{V}$ $I_{OH} = \text{MAX}$	2.4			V
V_{OL}	Low-level output voltage	$V_{CC} = \text{MIN}$ $V_{IH} = 2\text{V}$ $V_{IL} = 0.8\text{V}$ $I_{OL} = \text{MAX}$			0.5	V
I_I	Input current at maximum input voltage	$V_{CC} = \text{MAX}$ $V_I = 5.5 \text{ V}$			1.0	mA
I_{IH}	High-level input current	$V_{CC} = \text{MAX}$ $V_I = 2.4\text{V}$			25	μA
I_{IL}	Low-level input current	$V_{CC} = \text{MAX}$ $V_I = 0.4\text{V}$			-250	μA
I_{OS}	Short-circuit output current	$V_{CC} = \text{MAX}$ $V_O = 0\text{V}$	-30		-130	mA
I_{CC}	Supply current	$V_{CC} = \text{MAX}$		55	90	mA

Recommended Operating Conditions

Symbol	Parameter	Military			Commercial			Unit
		Min	Nom	Max	Min	Nom	Max	
V_{CC}	Supply voltage	4.5	5.0	5.5	4.75	5.00	5.25	V
I_{OH}	High-level output current			-2.0			-3.2	mA
I_{OL}	Low-level output current			8			8	mA
T_A	Operating free air temperature	-55		125	0		75	°C

Switching Characteristics

Over Recommended Ranges of Temperature and V_{CC}

Symbol	Parameter	Test Conditions†† R1 = 560Ω R2 = 1.1 kΩ	Military $T_A = -55^\circ \text{ to } +125^\circ \text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$			Commercial $T_A = 0^\circ \text{ to } 75^\circ \text{C}$ $V_{CC} = 5.0\text{V} \pm 5\%$			Unit
			Min	Typ	Max	Min	Typ	Max	
t_{PD}	From any input to any output	$C_L = 15\text{pF}$		25	45		25	35	ns

16L8, 16R8, 16R6, 16R4, 16X4, 16A4**Electrical Characteristics**

Over Recommended Operating Temperature Range

Symbol	Parameter		Test Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage			2			V
V_{IL}	Low-level input voltage					0.8	V
V_{IC}	Input clamp voltage		$V_{CC} = \text{MIN}$ $I_I = -18 \text{ mA}$			-1.5	V
V_{OH}	High-level output voltage		$V_{CC} = \text{MIN}$ $V_{IH} = 2\text{V}$ $V_{IL} = 0.8\text{V}$ $I_{OH} = \text{MAX}$	2.4			V
V_{OL}	Low-level output voltage		$V_{CC} = \text{MIN}$ $V_{IH} = 2\text{V}$ $V_{IL} = 0.8\text{V}$ $I_{OL} = \text{MAX}$			0.5	V
I_{OZH}	Off-state output current high-level voltage applied		$V_{CC} = \text{MAX}$, $V_{IH} = 2\text{V}$, $V_O = 2.4\text{V}$, $V_{IL} = 0.8\text{V}$			100	μA
I_{OZL}	Off-state output current low-level voltage applied		$V_{CC} = \text{MAX}$, $V_{IH} = 2\text{V}$, $V_O = 0.4\text{V}$, $V_{IL} = 0.8\text{V}$			-100	μA
I_I	Input current at maximum input voltage		$V_{CC} = \text{MAX}$ $V_I = 5.5 \text{ V}$			1.0	mA
I_{IH}	High-level input current		$V_{CC} \text{ MAX}$ $V_I = 2.4\text{V}$			25	μA
I_{IL}	Low-level input current		$V_{CC} \text{ MAX}$ $V_I = 0.4\text{V}$			-250	μA
I_{OS}	Short-circuit output current		$V_{CC} = \text{MAX}$ $V_O = 0\text{V}$	-30		-130	mA
I_{CC}	Supply Current	16L8	$V_{CC} = \text{MAX}$	140		180	mA
		16R4,16R6,16R8		150		180	

Recommended Operating Conditions

Symbol	Parameter	Military			Commercial			Unit
		Min	Nom	Max	Min	Nom	Max	
V_{CC}	Supply voltage	4.5	5.0	5.5	4.75	5.00	5.25	V
I_{OH}	High-level output current			-2.0			-3.2	mA
I_{OL}	Low-level output current			12			24	mA
T_A	Operating free air temperature	-55		125*	0		75	$^{\circ}\text{C}$

*Operating Case Temperature only, $T_C = 125^{\circ}\text{C}$

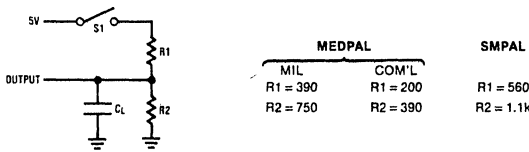
Switching Characteristics

Over Recommended Ranges of Temperature and V_{CC}

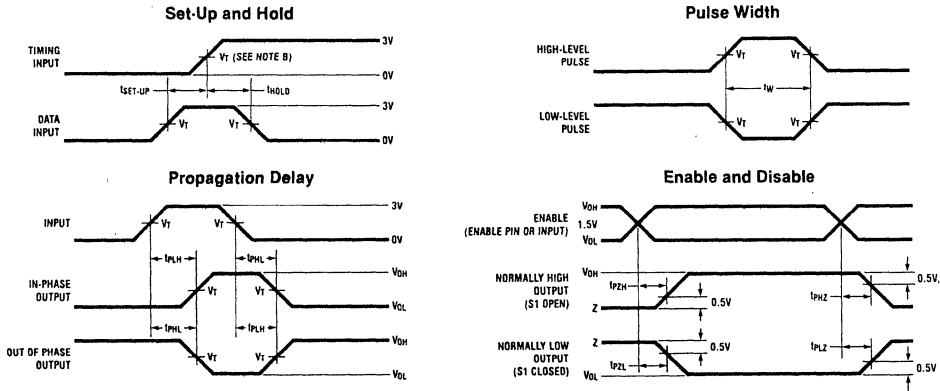
Symbol	Parameter		Test Conditions†† R1, R2	Military $T_A = -55^\circ \text{ to } +125^\circ \text{C}$ $V_{CC} = 5.0\text{V} \pm 10\%$			Commercial $T_A = 0^\circ \text{ to } 75^\circ \text{C}$ $V_{CC} = 5.0\text{V} \pm 5\%$			Unit
				Min	Typ	Max	Min	Typ	Max	
t_{PD}	Input to output		$C_L = 50\text{pF}$	25	45		25	35	ns	
t_{pD}	Clock to output			15	25		15	25	ns	
t_{pZX}	Pin 11 to output enable			15	25		15	25	ns	
t_{pXZ}	Pin 11 to output disable		$C_L = 5\text{pF}$	15	25		15	25	ns	
t_{pZX}	Input to output enable		$C_L = 50\text{pF}$	25	45		25	35	ns	
t_{pXZ}	Input to output disable		$C_L = 5\text{pF}$	25	45		25	35	ns	
t_w	Width of clock	High		25			25		ns	
		Low		25			25			
t_{su}	Setup time	16R8, 16R6, 16R4		45			35		ns	
		16X4, 16A4								
t_h	Hold time			0	- 15		0	- 15	ns	

††See Standard Test Load and Definition of Waveforms

Standard Test Load



Test Waveforms



Note A: C_L includes probe and jig capacitance.

Note B: $V_T = 1.5\text{V}$.

Note C: In the examples above, the phase relationships between inputs and outputs have been chosen arbitrarily.

Note D: All input pulses are supplied by generators having the following characteristics: PRR = 1 MHz, $Z_{OUT} = 50\Omega$.

Absolute Maximum Ratings

	Operating	Programming
Supply Voltage, V_{CC}	7V	12V
Input Voltage	5.5V	12V
Off-State Output Voltage	5.5V	12V
Storage Temperature Range	-65°C to +150°C	

10H8A, 12H6A, 14H4A, 16H2A, 16C1A, 10L8A, 12L6A, 14L4A, 16L2A

Recommended Operating Conditions

Symbol	Parameter	Military			Commercial			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{CC}	Supply Voltage	4.5	5	5.5	4.75	5	5.25	V
I_{OH}	High Level Output Current			-2			-3.2	mA
I_{OL}	Low Level Output Current			12			24	mA
T_A	Operating Free-Air Temperature				0		75	°C

Electrical Characteristics Over Recommended Operating Temperature Range

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{IH}	High Level Input Voltage		2			V
V_{IL}	Low Level Input Voltage				0.8	V
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min.}, I_I = -18\text{mA}$			-1.5	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min.}, V_{IH} = 2\text{V}$ $V_{IL} = 0.8\text{V}, I_{OH} = \text{Max.}$	2.4			V
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min.}, V_{IH} = 2\text{V}$ $V_{IL} = 0.8\text{V}, I_{OL} = \text{Max.}$			0.5	V
I_I	Input Current at Maximum Input Voltage	$V_{CC} = \text{Max.}, V_I = 5.5\text{V}$			1	mA
I_{IH}	High Level Input Current	$V_{CC} = \text{Max.}, V_I = 2.4\text{V}$			25	μA
I_{IL}	Low Level Input Current	$V_{CC} = \text{Max.}, V_I = 0.4\text{V}$			-0.25	μA
I_{OS}	Short Circuit Output Current	$V_{CC} = 5\text{V}$	-30		-130	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max.}$	55		90	mA

Switching Characteristics Over Recommended Ranges of Temperature and V_{CC}

Military: $T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$, $V_{CC} = 5\text{V} \pm 10\%$
 Commercial: $T_A = 0$ to 75°C , $V_{CC} = 5\text{V} \pm 5\%$

Symbol	Parameter	Test Conditions	Military			Commercial			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
t_{PD}	From any Input to any Output	$C_L = 15\text{pF}$		15	30		15	25	ns

16L8A, 16R8A, 16R6A, 16R4A, 16X4A, 16A4A

Recommended Operating Conditions

Symbol	Parameter		Military			Commercial			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
V _{CC}	Supply Voltage		4.5	5	5.5	4.75	5	5.25	V
t _w	Width of Clock	Low	20	10		15	10		ns
		High	20	10		15	10		
t _{su}	Setup Time from Input or Feedback to Clock	16R8A, 16R6A, 16R4A	30	16		25	16		ns
t _h	Hold Time		0	-10		0	-10		ns
T _A	Operating Free-Air Temperature		-55			0	25	75	°C
T _C	Operating Case Temperature				125				°C

Electrical Characteristics Over Recommended Operating Temperature Range

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{IH}	High Level Input Voltage		2			V
V _{IL}	Low Level Input Voltage				0.8	V
V _{IC}	Input Clamp Voltage	V _{CC} = Min., I _I = -18mA		-0.8	-1.5	V
V _{OH}	High Level Output Voltage	V _{CC} = Min. V _{IL} = 0.8V V _{IH} = 2V	2.4	2.8		V
		I _{OH} = -2mA MIL I _{OH} = -3.2mA COM				
V _{OL}	Low Level Output Voltage	V _{CC} = Min. V _{IL} = 0.8V V _{IH} = 2V		0.3	0.5	V
		I _{OL} = 12mA MIL I _{OL} = 24mA*** COM				
I _{OZH}	Off-state Output Current	V _{CC} = Max. V _{IL} = 0.8V V _{IH} = 2V			100	μA
I _{OZL}						
					-100	μA
I _I	Maximum Input Current	V _{CC} = Max., V _I = 5.5V			1	mA
I _{IH}	High Level Input Current	V _{CC} = Max., V _I = 2.4V			25	μA
I _{IL}	Low Level Input Current	V _{CC} = Max., V _I = 0.4V		-0.02	-0.25	mA
I _{OS}	Output Short-Circuit Current**	V _{CC} = 5V V _O = 0V	-30	-70	-130	mA
I _{CC}	Supply Current †	V _{CC} = Max.		120	180	mA

Switching Characteristics Over Recommended Ranges of Temperature and V_{CC}Military: T_A = -55°C to +125°C*, V_{CC} = 5V ± 10%Commercial: T_A = 0 to 75°C, V_{CC} = 5V ± 5%

Symbol	Parameter	Test Conditions†† R1, R2	Military			Commercial			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
t _{PD}	Input or Feedback to Output	C _L = 50pF		15	30		15	25	ns
t _{CLK}	Clock to Output or Feedback			10	20		10	15	
t _{PZX}	Pin 11 to Output Enable			10	25		10	20	
t _{PXZ}	Pin 11 to Output Disable	C _L = 5pF		11	25		11	20	ns
t _{PZX}	Input to Output Enable	C _L = 50pF		10	30		10	25	ns
t _{PXZ}	Input to Output Disable	C _L = 5pF		13	30		13	25	ns
f _{MAX}	Maximum Frequency		20	30		25	30	ns	

† I_{CC} = Max. at minimum temperature.

†† See Waveforms, Test Load on pg. 24-21.

Table 2-2. $T_A = 25^\circ\text{C}$

Symbol	Parameter		Limits			Units
			Min	Typ	Max	
V_{IHH}	Program-level input voltage		11.5	11.75	12.0	V
I_{IHH}	Program-level input current	Output Program Pulse			50	mA
		OD,L/R			25	
		All Other Inputs			5	
I_{CCH}	Program Supply Current				400	mA
T_p	Program Pulse Width		10		50	μs
t_d	Delay time		100			ns
	Program Pulse duty cycle				25	%
V_p	Program/Verify-Protect-input voltage $5.5\text{V} \leq V_{CC} \leq 6\text{V}$		18	18.5	19	V
I_p	Program/Verify-Protect-input current				400	mA
t_{dv}	Delay Time to Verify		100			μs

Programming

PAL fuses are programmed using a low-voltage linear-select procedure which is common to all 15 PAL types. The array is divided into two groups, products 0 through 31 and products 32 through 63, for which pin identifications are shown in Figure 2-2. To program a particular fuse, both an input line and a product line are selected according to the following procedure:

1. Raise Output Disable, OD, to V_{IHH} .
2. Select an input line by specifying $I_0, I_1, I_2, I_3, I_4, I_5, I_6, I_7$, and L/R as shown in Table 12.
3. Select a product line by specifying A_0, A_1 , and A_2 one-of-eight select as shown in Table 2-10.
4. Raise V_{CC} (pin 20) to V_{IHH} .
5. Program the fuse by pulsing the output pins O_n of the selected product group to V_{PH} as shown in Table 2-4.
6. Lower V_{CC} (pin 20) to 6.0 V.

7. Pulse the CLOCK pin and verify output pins O_n to be Low for active Low PAL types or High for active High PAL types.
8. Lower V_{CC} (pin 20) to 4.5 V and repeat step 7.
9. Should the output not verify, repeat steps 1 through 8 up to five (5) times.

Repeat this procedure for all fuses to be blown. (See Figure 2-3.)

To prevent further verification, two last fuses may be blown by raising pin 1 and pin 11 to 18.5 volts for 10 ms-1 sec. with V_{CC} at 6.0 volts.

Voltage Legend

L = Low-level input voltage, V_{IL}
 H = High-level input voltage, V_{IH}
 HH = High-level program voltage, V_{IHH}
 Z = 10 k Ohms to 5.0 V.

Table 2-3. Input Line Select

Input Line Number	Pin Identification								
	I ₇	I ₆	I ₅	I ₄	I ₃	I ₂	I ₁	I ₀	L/R
0	HH	HH	HH	HH	HH	HH	HH	L	Z
1	HH	HH	HH	HH	HH	HH	HH	H	Z
2	HH	HH	HH	HH	HH	HH	HH	L	HH
3	HH	HH	HH	HH	HH	HH	HH	H	HH
4	HH	HH	HH	HH	HH	HH	L	HH	Z
5	HH	HH	HH	HH	HH	HH	H	HH	Z
6	HH	HH	HH	HH	HH	HH	L	HH	HH
7	HH	HH	HH	HH	HH	HH	H	HH	HH
8	HH	HH	HH	HH	HH	L	HH	HH	Z
9	HH	HH	HH	HH	HH	H	HH	HH	Z
10	HH	HH	HH	HH	HH	L	HH	HH	HH
11	HH	HH	HH	HH	HH	H	HH	HH	HH
12	HH	HH	HH	HH	L	HH	HH	HH	Z
13	HH	HH	HH	HH	H	HH	HH	HH	Z
14	HH	HH	HH	HH	L	HH	HH	HH	HH
15	HH	HH	HH	HH	H	HH	HH	HH	HH
16	HH	HH	HH	L	HH	HH	HH	HH	Z
17	HH	HH	HH	H	HH	HH	HH	HH	Z
18	HH	HH	HH	L	HH	HH	HH	HH	HH
19	HH	HH	HH	H	HH	HH	HH	HH	HH
20	HH	HH	L	HH	HH	HH	HH	HH	Z
21	HH	HH	H	HH	HH	HH	HH	HH	Z
22	HH	HH	L	HH	HH	HH	HH	HH	HH
23	HH	HH	H	HH	HH	HH	HH	HH	HH
24	HH	L	HH	HH	HH	HH	HH	HH	R
25	HH	H	HH	HH	HH	HH	HH	HH	R
26	HH	L	HH	HH	HH	HH	HH	HH	HH
27	HH	H	HH	HH	HH	HH	HH	HH	HH
28	L	HH	HH	HH	HH	HH	HH	HH	Z
29	H	HH	HH	HH	HH	HH	HH	HH	Z
30	L	HH	HH	HH	HH	HH	HH	HH	HH
31	H	HH	HH	HH	HH	HH	HH	HH	HH

Table 2-4. Product Line Select

Product Line Number	Pin Identification						
	O ₃	O ₂	O ₁	O ₀	A ₂	A ₁	A ₀
0,32	Z	Z	Z	HH	Z	Z	Z
1,33	Z	Z	Z	HH	Z	Z	HH
2,34	Z	Z	Z	HH	Z	HH	Z
3,35	Z	Z	Z	HH	Z	HH	HH
4,36	Z	Z	Z	HH	HH	Z	Z
5,37	Z	Z	Z	HH	HH	Z	HH
6,38	Z	Z	Z	HH	HH	HH	Z
7,39	Z	Z	Z	HH	HH	HH	HH
8,40	Z	Z	HH	Z	Z	Z	Z
9,41	Z	Z	HH	Z	Z	Z	HH
10,42	Z	Z	HH	Z	Z	HH	Z
11,43	Z	Z	HH	Z	Z	HH	HH
12,44	Z	Z	HH	Z	HH	Z	Z
13,45	Z	Z	HH	Z	HH	Z	HH
14,46	Z	Z	HH	Z	HH	HH	Z
15,47	Z	Z	HH	Z	HH	HH	HH
16,48	Z	HH	Z	Z	Z	Z	Z
17,49	Z	HH	Z	Z	Z	Z	HH
18,50	Z	HH	Z	Z	Z	HH	Z
19,51	Z	HH	Z	Z	Z	HH	HH
20,52	Z	HH	Z	Z	HH	Z	Z
21,53	Z	HH	Z	Z	HH	Z	HH
22,54	Z	HH	Z	Z	HH	HH	Z
23,55	Z	HH	Z	Z	HH	HH	HH
24,56	HH	Z	Z	Z	Z	Z	Z
25,57	HH	Z	Z	Z	Z	Z	HH
26,58	HH	Z	Z	Z	Z	HH	Z
27,59	HH	Z	Z	Z	Z	HH	HH
28,60	HH	Z	Z	Z	HH	Z	Z
29,61	HH	Z	Z	Z	HH	Z	HH
30,62	HH	Z	Z	Z	HH	HH	Z
31,63	HH	Z	Z	Z	HH	HH	HH

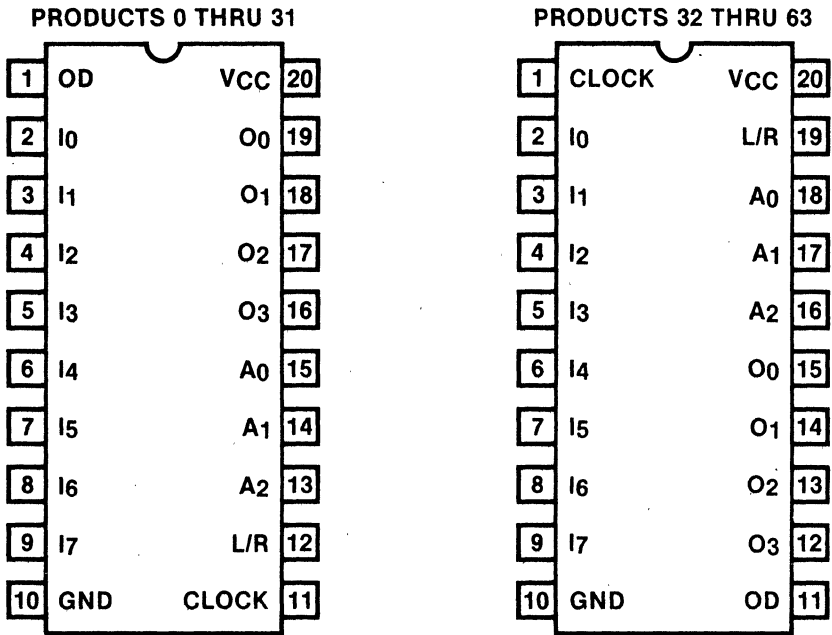


FIGURE 2-2. Pin Identification

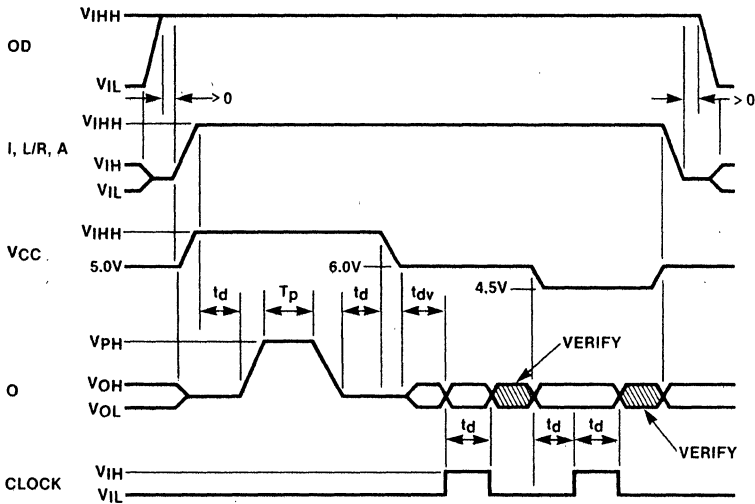


FIGURE 2-3. Programming Waveforms

Programmable Array Logic Series 24

General Description

The PAL[®] Series 24 family compliments the PAL Series 20 family by providing two additional inputs and two additional outputs, allowing more complex functions in a single package. This new family is made feasible by the new 300 Mil-wide, 24-pin package.

In addition to providing more logic functions per chip, 24 pins allow for many natural functions which were previously unavailable in 20-pin packages. Examples include:

- 8-bit parallel-in parallel-out counters
- 8-bit parallel-in parallel-out shift registers
- 16-Line-to-1-Line Multiplexers
- Dual 8-Line-to-1-Line Multiplexers
- Quad 4-Line-to-1-Line Multiplexers

These natural functions provide twice the density of traditional 16-pin packages.

The PAL family utilizes an advanced Schottky TTL process and the Bipolar PROM fusible link technology to provide user programmable logic for replacing conventional SSI/MSI gates and flip-flops at reduced chip count.

The family lets the systems engineer "design his own chip" by blowing fusible links to configure AND and OR gates to perform his desired logic function. Complex interconnections which previously required time-consuming layout are thus "lifted" from PC board etch and placed on silicon where they can be easily modified during prototype check-out or production. This often simplifies not only the PC board layout, but also the board itself.

The PAL transfer function is the familiar sum of products. Like the PROM, the PAL has a single array of fusible links. Unlike the PROM, the PAL is a programmable AND array driving a fixed OR array (the PROM is a fixed AND array driving a programmable OR array). In addition the PAL provides these options:

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- Variable input/output pin ratio
- Programmable three-state outputs
- Registers with feedback

Unused inputs are tied directly to V_{CC} or GND. Product terms with all fuses blown assume the logical high state, and product terms connected to both true and complement of any single input assume the logical low state. Registers consist of D type flip-flops which are loaded on the low to high transition of the clock. PAL Logic Diagrams are shown with all fuses blown, enabling the designer use of the diagrams as coding sheets.

The entire PAL family is programmed on inexpensive conventional PROM programmers with appropriate personality cards and socket adapters. Once the PAL is programmed and verified, two additional fuses may be blown to defeat verification. This feature gives the user a proprietary circuit which is very difficult to copy.

Features

- Programmable replacement for conventional TTL logic.
- Reduces IC inventories substantially and simplifies their control.
- Reduces chip count by 5 to 1, typically.
- Expedites and simplifies prototyping and board layout.
- Saves space with 300 Mil-wide, 24-pin DIP packages.
- Programmed on standard PROM programmers.
- Programmable three-state outputs.
- Last fuse reduces possibility of copying by competitors.

Table 2-5. Part Types

Part Number	Description
DMPAL12L10	DECA 12 Input AND-OR-INVERT Gate Array
DMPAL14L8	OCTAL 14 Input AND-OR-INVERT Gate Array
DMPAL16L6	HEX 16 Input AND-OR-INVERT Gate Array
DMPAL18L4	QUAD 18 input AND-OR-INVERT Gate Array
DMPAL20L10	DECA 20 Input AND-OR-Invert Gate Array
DMPAL20X10	DECA 20 Input Registered AND-OR-XOR Gate Array
DMPAL20X8	OCTAL 20 Input Registered AND-OR-XOR Gate Array
DMPAL20X4	QUAD 20 Input Registered AND-OR-XOR Gate Array
DMPAL20L2	DUAL 20 Input AND-OR-INVERT Array
DMPAL20C1	SINGLE 20 Input AND-OR-INVERT Array

Absolute Maximum Ratings

	Operating	Programming
Supply Voltage, V_{CC}	7V	12V
Input Voltage	5.5V	12V*
Off-state Output Voltage	5.5V	12V
Storage Temperature	-65°C to +150°C	

Operating Conditions

Symbol	Parameter	Military			Commercial			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
V_{CC}	Supply Voltage	4.5	5	5.5	4.75	5	5.25	V
T_A	Operating Free-air Temperature				0		75	°C
T_C	Operating Case Temperature	-55		125				°C

Electrical Characteristics Over Operating Conditions

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
V_{IL}	Low Level Input Voltage				0.8	V	
V_{IH}	High Level Input Voltage		2			V	
V_{IC}	Input Clamp Voltage	$V_{CC} = \text{Min.}$ $I_I = -18\text{mA}$			-1.5	V	
I_{IL}	Low Level Input Current †	$V_{CC} = \text{Max.}$ $V_I = 0.4\text{V}$			-0.25	mA	
I_{IH}	High Level Input Current †	$V_{CC} = \text{Max.}$ $V_I = 2.4\text{V}$			25	μA	
I_I	Maximum Input Current	$V_{CC} = \text{Max.}$ $V_I = 5.5\text{V}$			1	mA	
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min.}$ $V_{IL} = 0.8\text{V}$ $V_{IH} = 2\text{V}$	$I_{OL} = 12\text{ mA}$	MIL	0.5	V	
			$I_{OL} = 24\text{ mA}$	COM			
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min.}$ $V_{IL} = 0.8\text{V}$ $V_{IH} = 2\text{V}$	$I_{OH} = -2\text{ mA}$	MIL	2.4	V	
			$I_{OH} = -3.2\text{mA}$	COM			
I_{OZL}	Off-state Output Current †	$V_{CC} = \text{Max.}$ $V_{IL} = 0.8\text{V}$ $V_{IH} = 2\text{V}$	$V_O = 0.4\text{V}$		-100	μA	
I_{OZH}			$V_O = 2.4\text{V}$		100	μA	
I_{OS}	Output Short-Circuit Current**	$V_{CC} = \text{Max.}$	$V_O = 0\text{V}$		-30	-130	mA
I_{CC}	Supply Current	$V_{CC} = \text{Max.}$	20X4, 20X8, 20X10		120	180	mA
			20L10		90	165	

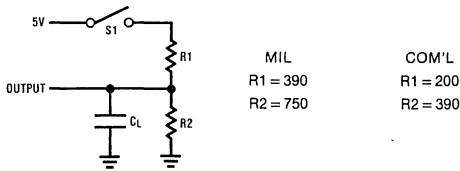
† I/O pin leakage is the worst case of I_{OZX} or I_{IX} , e.g. I_{IL} and I_{OZH} .
Pins 1 and 13 may be raised to 22V max.

** Only one output shorted at a time.

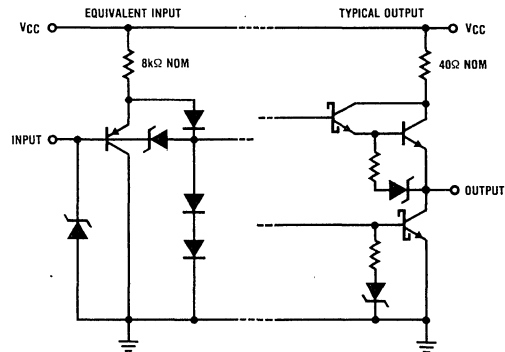
Switching Characteristics Over Operating Conditions

Symbol	Parameter	Test Conditions R1, R2	Military			Commercial			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
t_{PD}	Input or Feedback to Output	20L10, 20X10 20X8, 20X4 $C_L = 50$ pF		35	60		35	50	ns
t_{PD}	Input or Feedback to Output	12L10, 14L8, 16L6 18L4, 20L2, 20C1 $C_L = 50$ pF		25	45		25	40	ns
t_{CLK}	Clock to Output or Feedback	$C_L = 50$ pF		20	40		20	30	ns
t_{PZX}	Pin 13 to Output Enable	$C_L = 50$ pF		20	45		20	35	ns
t_{PXZ}	Pin 13 to Output Disable	$C_L = 5$ pF		20	45		20	35	ns
t_{PZX}	Input to Output Enable	$C_L = 50$ pF		35	55		35	45	ns
t_{PXZ}	Input to Output Disable	$C_L = 5$ pF		35	55		35	45	ns
t_W	Width of Clock	Low		30			25		ns
		High		40			35		ns
t_{SU}	Set-Up Time from Input or Feedback			60			50		ns
t_h	Hold Time			0	-15		0	-15	ns
f_{MAX}	Maximum Frequency			10.0			12.5		MHz

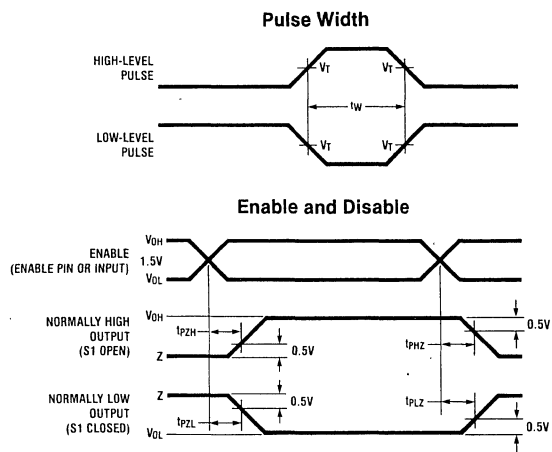
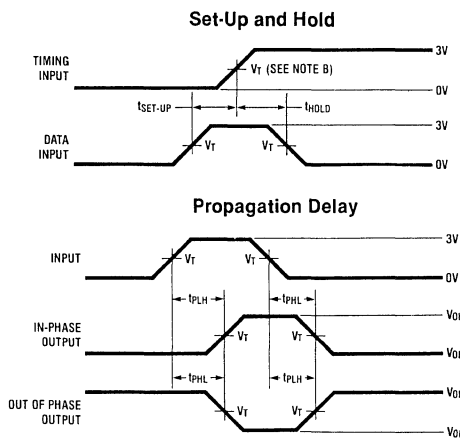
Test Load



Schematic of Inputs and Outputs



Test Waveforms



Note A: C_L includes probe and jig capacitance.

Note B: $V_T = 1.5V$.

Note C: In the examples above, the phase relationships between inputs and outputs have been chosen arbitrarily.

Note D: All input pulses are supplied by generators having the following characteristics: PRR = 1 MHz, $Z_{OUT} = 50\Omega$.

Programming

PAL fuses are programmed using a low-voltage linear-select procedure which is common to all PAL types. The array is divided into two groups, products 0 thru 39 and products 40 thru 79, for which pin identifications are shown in Pin Configurations below. To program a particular fuse, both an input line and a product line are selected according to the following procedure:

- Step 1 Raise Output Disable, OD, to V_{IHH} .
- Step 2 Select an input line by specifying $I_0, I_1, I_2, I_3, I_4, I_5, I_6, I_7, I_8, I_9$ and L/R as shown in Table 2-6.
- Step 3 Select a product line by specifying A_0 and A_1 one-of-four select as shown in Table 2-7.
- Step 4 Raise V_{CC} (pin 24) to V_{IHH} .
- Step 5 Program the fuse by pulsing the output pins, O, of the selected product group to V_{IHH} as shown in Programming Waveform.

- Step 6 Lower V_{CC} (pin 24) to 6.0 V.
- Step 7 Pulse the CLOCK pin and verify the output pin, O, to be Low for active Low PAL types or High for active High PAL types.
- Step 8 Lower V_{CC} (pin 24) to 4.5 V and repeat Step 7.
- Step 9 Should the output not verify, repeat steps 1 thru 8 up to five (5) times.

This procedure is repeated for all fuses to be blown (see Programming Waveforms).

To prevent further verification, two last fuses may be blown by raising pin 1 and pin 13 to 18.5 volts with V_{CC} at 6.0 volts.

Voltage Legend

L = Low Level Input Voltage, V_{IL}
 H = High Level Input Voltage, V_{IH}

HH = High Level Program Voltage, V_{IHH}
 Z = High Impedance (e.g. 10k Ω to 5.0V)

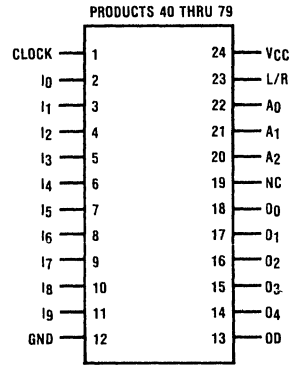
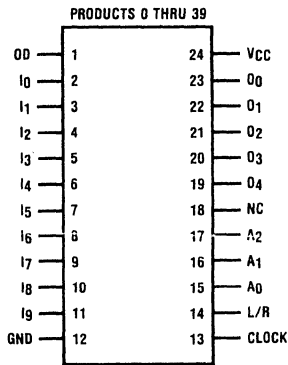
Table 2-6. Input Line Select

Input Line Number	Pin Identification											
	I_9	I_8	I_7	I_6	I_5	I_4	I_3	I_2	I_1	I_0	L/R	
0	HH	HH	HH	HH	HH	HH	HH	HH	HH	L	Z	
1	HH	HH	HH	HH	HH	HH	HH	HH	HH	H	Z	
2	HH	HH	HH	HH	HH	HH	HH	HH	L	HH		HH
3	HH	HH	HH	HH	HH	HH	HH	HH	H	HH		HH
4	HH	HH	HH	HH	HH	HH	HH	L	HH	Z		
5	HH	HH	HH	HH	HH	HH	HH	H	HH	Z		
6	HH	HH	HH	HH	HH	HH	HH	L	HH	HH		
7	HH	HH	HH	HH	HH	HH	HH	H	HH	HH		
8	HH	HH	HH	HH	HH	HH	L	HH	HH	Z		
9	HH	HH	HH	HH	HH	HH	H	HH	HH	Z		
10	HH	HH	HH	HH	HH	HH	L	HH	HH	HH		
11	HH	HH	HH	HH	HH	HH	H	HH	HH	HH		
12	HH	HH	HH	HH	HH	L	HH	HH	HH	Z		
13	HH	HH	HH	HH	HH	H	HH	HH	HH	Z		
14	HH	HH	HH	HH	HH	L	HH	HH	HH	HH		
15	HH	HH	HH	HH	HH	H	HH	HH	HH	HH		
16	HH	HH	HH	HH	L	HH	HH	HH	HH	Z		
17	HH	HH	HH	HH	H	HH	HH	HH	HH	Z		
18	HH	HH	HH	HH	L	HH	HH	HH	HH	HH		
19	HH	HH	HH	HH	H	HH	HH	HH	HH	HH		
20	HH	HH	HH	HH	L	HH	HH	HH	HH	HH	Z	
21	HH	HH	HH	HH	H	HH	HH	HH	HH	HH	Z	
22	HH	HH	HH	L	HH	HH	HH	HH	HH	HH	HH	
23	HH	HH	HH	HH	H	HH	HH	HH	HH	HH	HH	
24	HH	HH	HH	L	HH	HH	HH	HH	HH	HH	Z	
25	HH	HH	HH	H	HH	HH	HH	HH	HH	HH	Z	
26	HH	HH	HH	L	HH	HH	HH	HH	HH	HH	HH	
27	HH	HH	HH	H	HH	HH	HH	HH	HH	HH	HH	
28	HH	HH	L	HH	HH	HH	HH	HH	HH	HH	Z	
29	HH	HH	H	HH	HH	HH	HH	HH	HH	HH	Z	
30	HH	HH	L	HH	HH	HH	HH	HH	HH	HH	HH	
31	HH	HH	H	HH	HH	HH	HH	HH	HH	HH	HH	
32	HH	L	HH	HH	HH	HH	HH	HH	HH	HH	Z	
33	HH	H	HH	HH	HH	HH	HH	HH	HH	HH	Z	
34	HH	L	HH	HH	HH	HH	HH	HH	HH	HH	HH	
35	HH	H	HH	HH	HH	HH	HH	HH	HH	HH	HH	
36	L	HH	HH	HH	HH	HH	HH	HH	HH	HH	Z	
37	H	HH	HH	HH	HH	HH	HH	HH	HH	HH	Z	
38	L	HH	HH	HH	HH	HH	HH	HH	HH	HH	HH	
39	H	HH	HH	HH	HH	HH	HH	HH	HH	HH	HH	

Table 2-7. Product Line Select

Product Line Number	Pin Identification							
	O_4	O_3	O_2	O_1	O_0	A_2	A_1	A_0
0, 40	Z	Z	Z	Z	HH	Z	Z	Z
1, 41	Z	Z	Z	Z	HH	Z	Z	HH
2, 42	Z	Z	Z	Z	HH	Z	HH	Z
3, 43	Z	Z	Z	Z	HH	Z	HH	HH
8, 48	Z	Z	Z	HH	Z	Z	Z	Z
9, 49	Z	Z	Z	HH	Z	Z	Z	HH
10, 50	Z	Z	Z	HH	Z	Z	HH	Z
11, 51	Z	Z	Z	HH	Z	Z	HH	HH
16, 56	Z	Z	HH	Z	Z	Z	Z	Z
17, 57	Z	Z	HH	Z	Z	Z	Z	HH
18, 58	Z	Z	HH	Z	Z	Z	HH	Z
19, 59	Z	Z	HH	Z	Z	Z	HH	HH
24, 64	Z	HH	Z	Z	Z	Z	Z	Z
25, 65	Z	HH	Z	Z	Z	Z	Z	HH
26, 66	Z	HH	Z	Z	Z	Z	HH	Z
27, 67	Z	HH	Z	Z	Z	Z	HH	HH
32, 72	HH	Z	Z	Z	Z	Z	Z	Z
33, 73	HH	Z	Z	Z	Z	Z	Z	HH
34, 74	HH	Z	Z	Z	Z	Z	HH	Z
35, 75	HH	Z	Z	Z	Z	Z	HH	HH
36, 76	HH	Z	Z	Z	Z	HH	Z	Z
37, 77	HH	Z	Z	Z	Z	HH	Z	HH
38, 78	HH	Z	Z	Z	Z	HH	HH	Z
39, 79	HH	Z	Z	Z	Z	HH	HH	HH

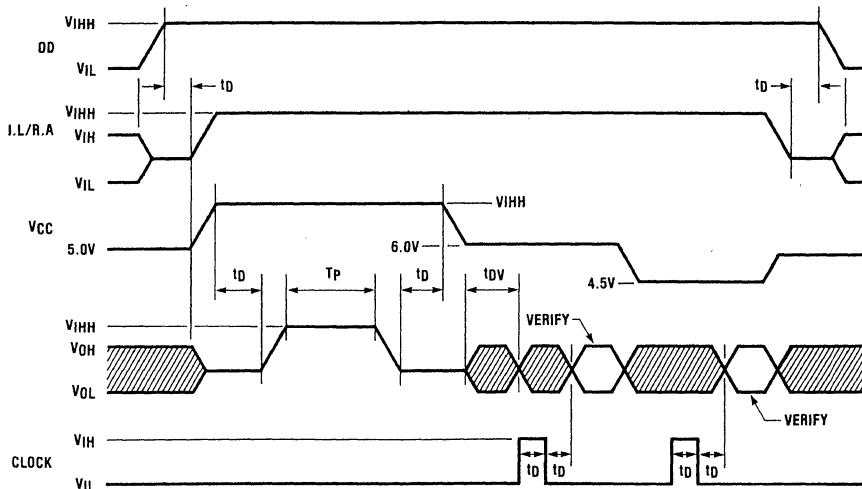
Pin Configurations



Programming Parameters $T_A = 25^\circ\text{C}$

Symbol	Parameter	Limits			Unit
		Min.	Typ.	Max.	
V_{IHH}	Program-level Input Voltage	11.5	11.75	12.0	V
I_{IHH}	Program-level Input Current	Output Program Pulse		50	mA
		OD, L/R		50	
		All Other Inputs		5	
I_{CCH}	Program Supply Current			400	mA
T_P	Program Pulse Width	10		50	μs
t_D	Delay Time	100			ns
t_{DV}	Delay Time to Verify	100			μs
	Program Pulse Duty Cycle			25	%
V_P	Verify-Protect Input Voltage $5.5\text{V} \leq V_{CC} \leq 6.0\text{V}$	18	18.5	19	V
I_P	Verify-Protect Input Current			400	mA
T_{PP}	Verify-Protect Pulse Width	20		50	ms

Programming Waveforms



PAL Design

Selecting the Right PAL

PAL part types come in small, medium, and large sizes, offering a wide range of complexities. The small PALs are also referred to as combinational because they just do logic functions. Four of these small PALs have active-high outputs (the "H" series), and four have active-low outputs (the "L" series), with a variety of input/output pin ratios. The one small PAL left over is the 16C1, which has complementary outputs. The small PAL types can replace random SSI gate functions at about a 4-to-1 chip-count reduction. This group is designed to provide low-power Schottky (LS) fan-out and fan-in characteristics of 8 mA output sink (I_{OL}) for totem-pole outputs and 0.25 mA input loading (I_{IL}).

The simplest medium PAL, the 16L8, is logically the same as the 10L8, with six added inputs that are shared with output pins. The 16 in its type number thus refers to the number of input variables to its AND matrix. Its unique logic is shown in Figure 3-2. Its TRI-STATE® outputs are controlled by lines from the AND matrix, so can be acted upon by input variables. These pins therefore serve as I/O in a bus-oriented environment.

Other medium PALs are the R (Register) devices. Figure 3-3 is a simplified diagram showing the logic embodied in the R series. The unique feature of the Register PAL is the D-type register element following each OR gate. A common clock input latches data into all register elements simultaneously on the rising edge of the clock pulse. The register outputs are connected to TRI-STATE buffers, controlled by a common enable input.

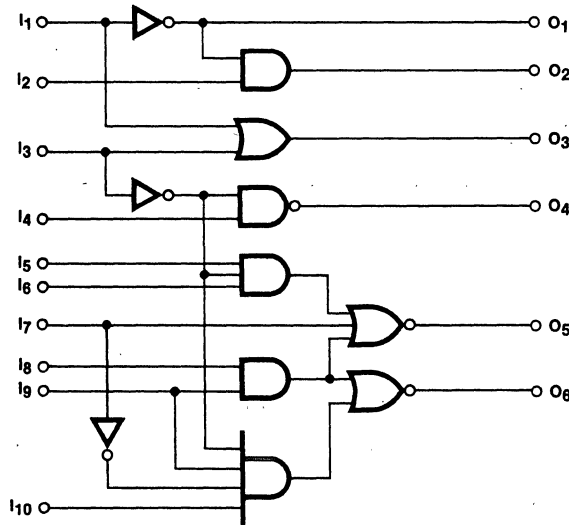


FIGURE 3-1. Typical Combinational Logic Application.

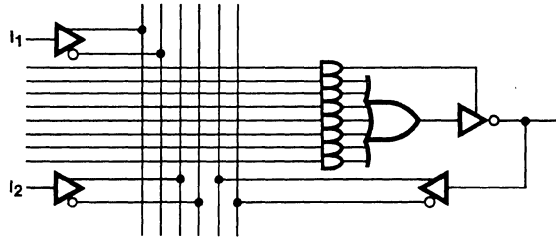


FIGURE 3-2. Simplified Logic Diagram of the 16L8 PAL®

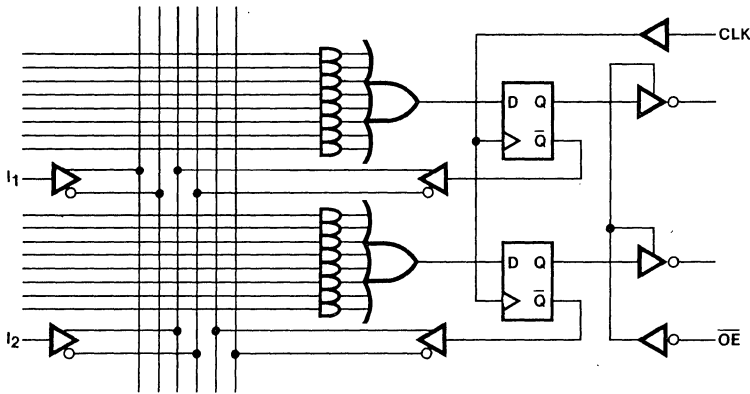


FIGURE 3-3. Logic of the R Series PAL®

A significant feature of the register PALs is the register feedback path to the AND matrix. This feedback path allows the PALs to be used in state-machine applications in which the feedback loops are all on-chip. These devices are especially useful in the design of custom registers, shifters, and counters.

The three register PALs are the 16R8, 16R6, and 16R4, which have eight, six, and four register elements, respectively. Each has eight outputs; those not serving the register elements are of the I/O variety, like those on the 16L8, above. Their outputs are bus drivers that will deliver the standard LS output sink of 24 mA (I_{OL}).

Two members of the PAL family (16x4 and 16A4) are referred to as large PALs. These two devices facilitate the arithmetic functions, add, subtract, greater than, and less than, by means

of the two additional features shown in Figure 3-4. The sum of the products (OR outputs) is segmented into two, which are then XOR'd to the D flip-flop input. This allows carries from previous operations to be XOR'd with the two variable sums generated by the AND array.

A second feature is the gating of the register feedback path and inputs, forming the terms $I + Q$, $I + \bar{Q}$, $\bar{I} + Q$, and $\bar{I} + \bar{Q}$. This provides versatile operations on two variables and facilitates the parallel generation of carries. These two parts also have bus-driver outputs. You can expect "compression ratios" (package count reductions) of up to 12:1 by comparison with existing combinations of MSI and discretes. You can also invent new and unique LSI functions with these parts, and implement them without having to spend huge sums on masks or tooling.

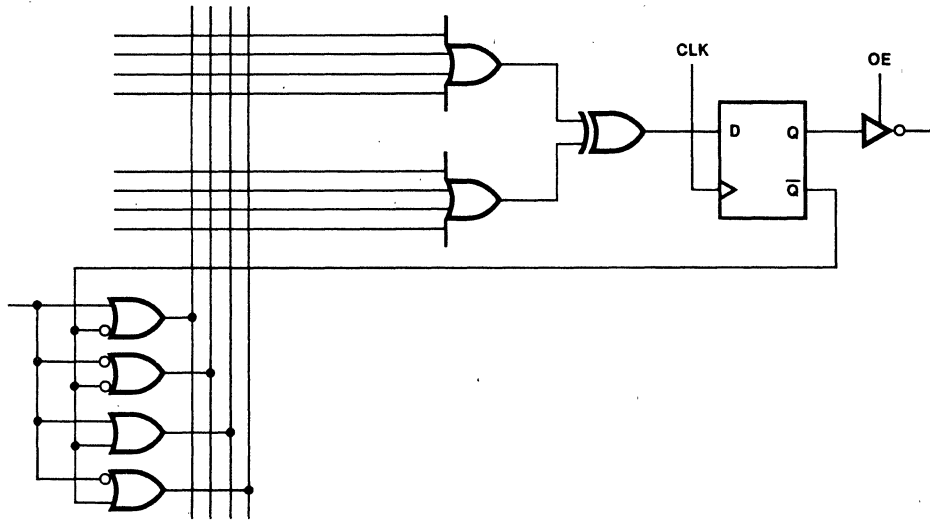


FIGURE 3-4. Logic of the Large PAL®

Designing the PAL Once a particular PAL device is selected, it is time to generate the PAL design. This can be done either manually or through the use of a software tool called PALASM™, described on page 24-41.

coding a PAL. Since no registers are called for, the device to implement this function may be selected from among the H, L, and C types. Since the lower part of the diagram displays AND-OR-INVERT functions, the L series is most likely.

The coding conventions adopted to describe PAL programming are described in Figure 3-20. The arbitrary circuit of Figure 3-21 is used as a design example for selecting and

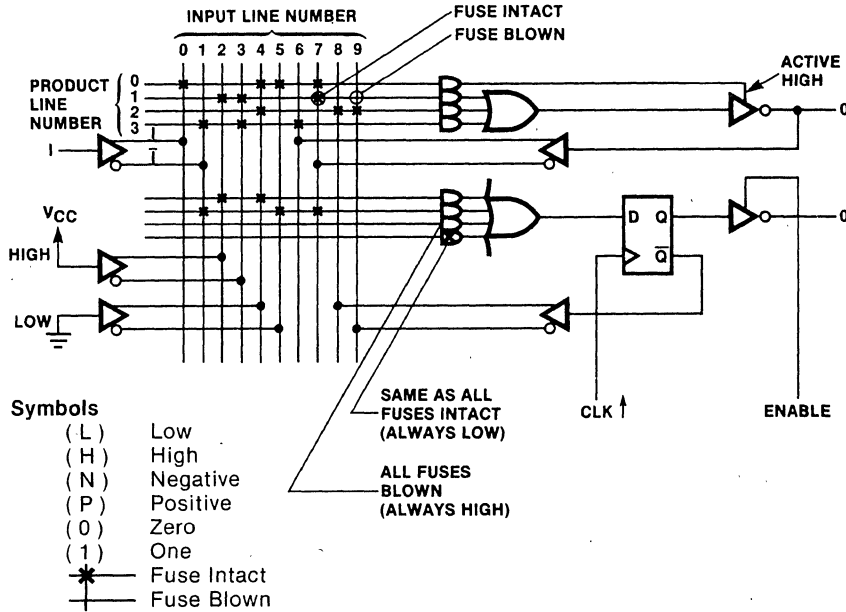


FIGURE 3-20. Coding Conventions.

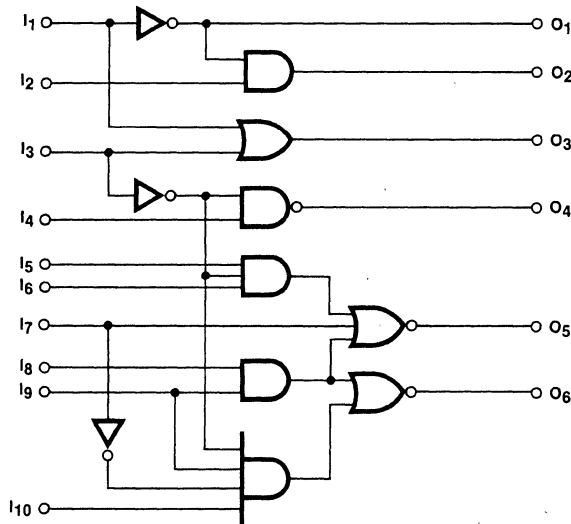


FIGURE 3-21. Design Example, Logic Diagram.

The next step: the number of inputs (10) and the number of outputs (6) indicates that a 10L8, 12L6, or 16LB could accommodate the entire circuit. Since the 10L8 and 12L6 are "small" PALs and hence less costly than the 16L8 "medium" device, the choice should be made between these two if possible. A review of the 10L8's logic diagram shows that all of its NOR gates are two-input gates, and the design example requires a three-input gate. On the other hand, the 12L6 has two 4-input gates which will accommodate the three-input requirement. It, therefore, is selected. Having chosen an inverting type of PAL, you apply DeMorgan's theorem to handle the inversion at the NOR gates feeding all of its outputs. Demorgan's theorem can be used to convert any logic form to the AND-OR/AND-NOR PAL format. This has been done in the equations below; the PAL AND-NOR format shown on the right.

$$O_1 = \overline{I_1} \quad \equiv \quad \overline{I_1} = I_1 \quad (1)$$

$$O_2 = \overline{I_1 \cdot I_2} \quad \equiv \quad \overline{I_2} = I_1 + I_2 \quad (2)$$

$$O_3 = I_1 + I_3 \quad \equiv \quad \overline{I_3} = \overline{I_1} \cdot \overline{I_3} \quad (3)$$

$$O_4 = \overline{\overline{I_3} \cdot I_4} \quad \equiv \quad \overline{I_4} = \overline{I_3} \cdot I_4 \quad (4)$$

$$O_5 = \overline{\overline{I_3} \cdot I_5 \cdot I_6 + I_7 + I_8 \cdot I_9}$$

$$\quad \equiv \quad \overline{I_5} = \overline{I_3} \cdot I_5 \cdot I_6 + I_7 + I_8 \cdot I_9 \quad (5)$$

$$O_6 = \overline{\overline{I_8} \cdot I_a + \overline{I_3} \cdot \overline{I_7} \cdot I_9 \cdot I_{10}}$$

$$\quad \equiv \quad \overline{I_6} = \overline{I_8} \cdot I_9 + \overline{I_3} \cdot \overline{I_7} \cdot I_9 \cdot I_{10} \quad (6)$$

Assuming that there are no board layout constraints, input I_1 through I_{10} may be assigned to pins 1 through 11. (Pin 10 is ground.) The only constraint on output pin assignment is that O_5 must be assigned to pin 13 or 18 to take advantage of one of the 4-input NOR gates.

O_1 is assigned to pin 18. To make this output the inverse of I_1 , leave input line 2 connected (not blown) to product line 8 and blow all the remaining fuses on that product line. This is indicated by the X on the intersection of input line 2 and product line 8 in Figure 3-24.

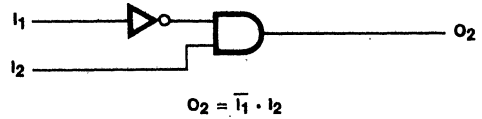


FIGURE 3-22. The Logic Diagram and Expression for Output 2.

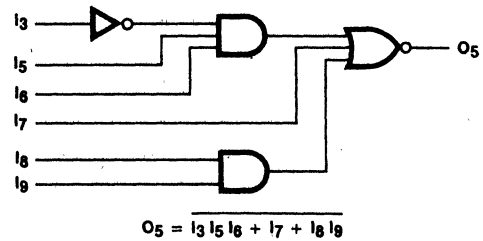


FIGURE 3-23. The Logic Diagram and Expression for Output 5.

As the other three inputs to NOR gate 1 are not used, they are forced to zero by leaving all fuses intact on product lines 9, 10, and 11. (As shown in Figure 3-20, instead of confusing the diagram with many Xs, the unused inputs are indicated by Xs in the small AND symbols at the NOR gate inputs.)

The next output, O_2 , is the AND function of I_1 and I_2 (Figure 3-22). In the L series, the AND gates cannot be brought to outputs without inversion, but by DeMorgan's theorem, the equivalent function can be constructed by taking the complements of the two inputs, ORing them, and inverting the result. Equation (2), on Page 24-36 shows the form that can be coded directly into the 12L6. The coding of this expression, using pin 1 and the complement of pin 2 as inputs 1 and 2, respectively, and pin 17 as output 2, is marked with Xs on product lines 1 and 2 in Figure 3-24.

Output O_3 is the OR of I_1 and I_3 . Again, the output inversion of the L series suggests the double-inversion application of DeMorgan's theorem, as shown in Equation (3). To do this, connect input lines 3 (I_1) and 5 (I_3) to product line 24. Since no other input is needed to NOR gate 3, its other input is forced low by leaving all its fuses intact. The X at the unused gate input shows this on the diagram.

Output O_4 is the NAND function of I_3 and I_4 . This is accomplished by ANDing input line 5 (I_3) and input line 8 (I_4) on product line 32, which produces $/(I_3 \cdot I_4)$ at the output of NOR gate 4, with its unused input tied to 0 (all fuses intact).

Output O_5 is generated by ANDing I_3 , I_5 , and I_6 on product line 48, ANDing I_8 and I_9 on line 50, connecting I_7 to product line 49, and leaving unused line 51 grounded. (See Figures 3-23 and 3-24.)

Output O_6 is generated by ANDing I_8 and I_9 on product line 40 and I_3 , I_7 , I_9 , and I_{10} on product line 41, which, inverted by NOR gate 5, results in $/O_6$. [See Equation (6).]

The coding for a completed PAL design must be transformed into a format more readily interpreted for execution on commercially available PROM programming devices. A form for doing this is shown in Figure 3-25. The numbers along the top of the figure correspond with the input line numbers that appear across the top of the logic diagram (Figure 3-24). The product term line numbers along the left side of these two illustrations correspond also.

Note that some of the boxes in Figure 3-25 are filled in with Gothic L's. These represent phantom fuses, which are fuse locations not accessible in the given device type but which must be accounted for to provide the programmer with the proper data for verification. For the present, these entries can be ignored. To fill in the remaining boxes, begin with the first X marked on the logic diagram, Figure 3-24. It is located at the intersection of input line 2 and product term 8. Since this is an intact fuse, an L (for Low) is entered in the corresponding box of Figure 3-25, as detailed below.

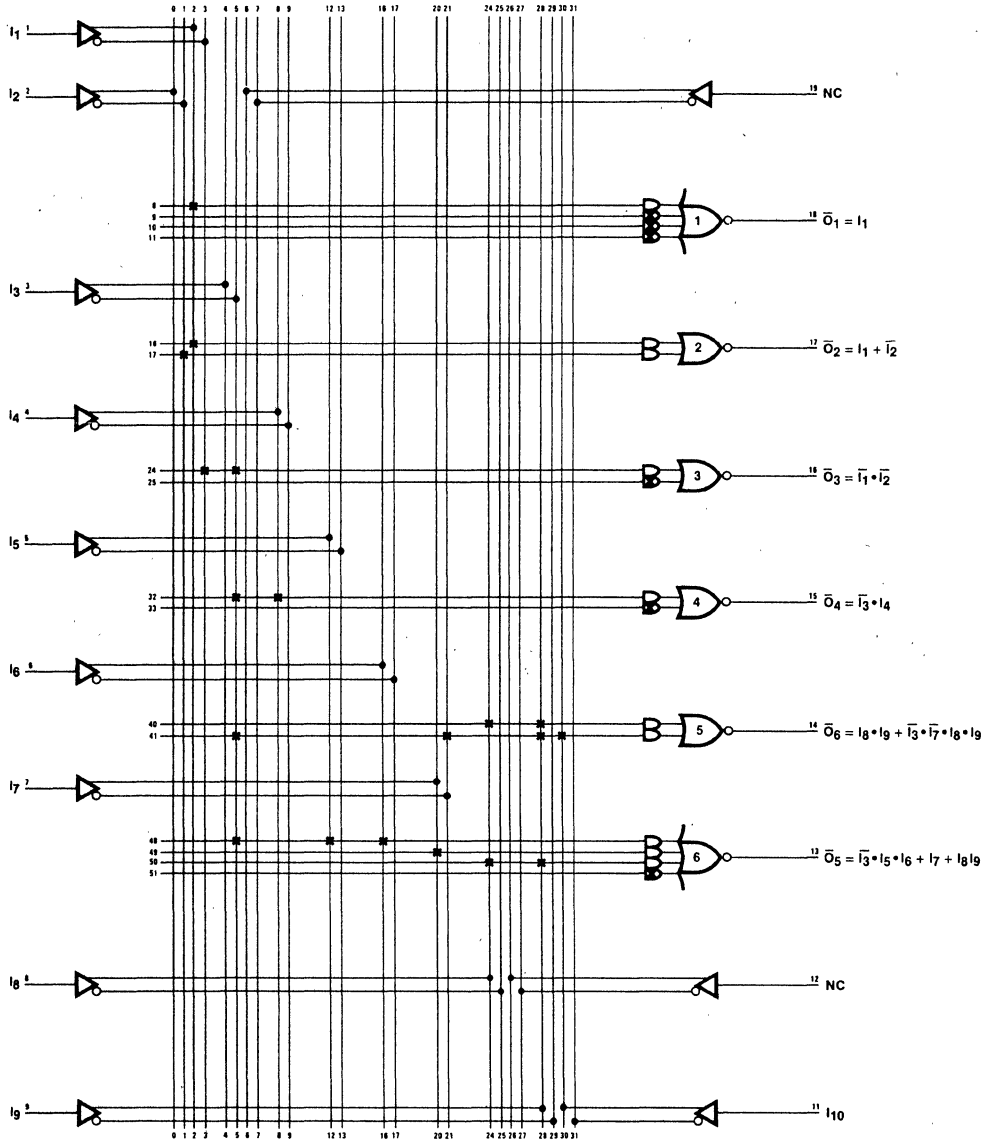
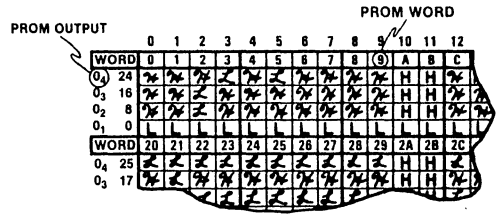
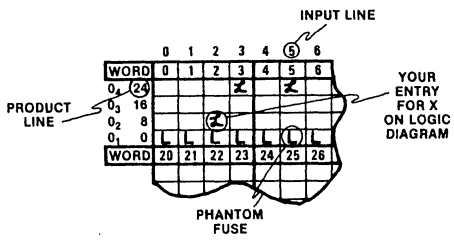


FIGURE 3-24. Logic Diagram of the National Type 12L6 PAL®



NOTE

Script L's (L) are used to differentiate entries being programmed and entries already on the form. In practice, this is not necessary.

Next L's are entered in all of the blank spaces for product term 9 on the form (Fig. 3-25), since this is an unused line, as indicated by the X at the input to the NOR gate for this product term on the logic diagram. Similarly, complete lines of L's are entered for product terms 10 and 11. Every X on the logic diagram must be entered on the PAL programming form as an L or, in the case of the unused gate inputs, as a row of L's. Figure 3-25 is shown with all the necessary L's filled in.

Since all of the remaining fuses are to be blown, H's must be written into the remaining blanks. For clarity, this is not done in Figure 3-25, but a portion of the completed programming format is shown below.

Once the programming format is complete, the input line and product term numbers can be forgotten. What the format sheet does is translate these into their equivalent hexadecimal input words and outputs, in the form

acceptable by a device that programs 512 x 4 PROMs. Thus, to program the example currently under discussion, insert the 12L6 PAL into the socket of a suitably configured programmer and enter the following:

Word No.	Output		
	O ₄	O ₃	O ₂ O ₁
0	H	H	L
1	H	H	L
2	H	L	L
3	L	H	L
4	H	H	L
5	L	H	L
6	H	H	L
•	•	•	•
•	•	•	•
•	•	•	•
1F	H	H	L
20	L	H	L
21	L	L	L
22	L	H	L
•	•	•	•
•	•	•	•
•	•	•	•
1FF	L	L	L

After the PAL is programmed and verified, it must be tested logically in the PAL mode to eliminate defects which cannot be tested at the factory prior to programming.

Executing this sequence programs a Type 12L6 PAL to implement the logic function shown in Figure 3-21. Programming format sheets and logic diagrams that show all fuse locations for all 15 of the PAL devices are shown later in this section.

Phantom Fuses

Phantom fuse locations are those locations where a fuse does not exist. These are revealed as missing outputs, missing product terms, or missing input lines in the logic diagrams, Figures 3-5 through 3-19. PALs with phantom fuse locations appear the same to the programming device as partially programmed 512 x 4 PROMs. As the programmer expects to verify all 2048 locations, the PAL programming format must provide the expected pattern for verifying nonexistent fuse nodes. When filling out the programming format, refer to Figure 3-26, the key to phantom fuse locations in the complete logic schematics that follow.

PALASM TM

Manual PAL coding, while practical for one or two designs, is far too tedious and error-prone for continual use. What is needed is a computer-aided design technique that automates the design process to the highest degree possible. One such design aid is a FORTRAN-IV-based software package called PALASM. This design aid allows PALs to be

designed by writing logic equations to represent the desired logic function. The output of PALASM is a programming tape that can be used as a data input by most PROM programmers that have PAL personality cards. Its output format can be BHLF, BPNF, or Hexadecimal.

The simplest way to describe PALASM is with a design example. The same arbitrary sample function that is described on the previous pages is "designed" using PALASM in the discussion that follows. The logic diagram is shown in Figure 3-21. Figure 3-27 shows the logic operators recognized by the assembler. Figure 3-28 is the input to PALASM that is compiled by the program and generates the code for the programming device.

- = Equal
- := Replaced by, following clock
- / Complement
- ★ AND, PRODUCT
- + OR, SUM
- +: XOR
- :★: XNOR
- () Conditional TRI-STATE IF statement, arithmetic

FIGURE 3-27. PALASM Operators

	Active High Logic		Active Low Logic	
	(PAL 10H8, 12H6, 14H4, 16H2)	LEGEND	(PAL 10L8, 12L6, 14L4, 16L2)	LEGEND
1) Missing Output	H (P,1)	⊕	L (N,O)	⊖
2) Missing product	L (N,O)	⊖	L (N,O)	⊖
3) Missing input lines	H (P,1)	⊕	H (P,1)	⊕

Note 1: Missing product term overrides missing input line.

Note 2: For PAL 16C1, first half of the array (product terms 0-31) acts as active high logic and the second half of the array (product terms 32-63) acts as active low logic device.

FIGURE 3-26. PAL Phantom Fuse Symbology.

The PALASM program is instructed to generate code with which to program the 12L6 by keying the sequence shown in Figure 3-28 into its host computer as follows:

Line 1: At the left margin, the PAL device is specified. For this example, the 12L6 remains the best solution. "PAL DESIGN SPECIFICATION" is entered at the right.

Line 2: A unique pattern number for this PAL design is entered at the left margin on line 2, followed by designer's name and date.

Line 3: The name or description of the device or function is entered. If this runs over one line, Line 4 may be used to complete it.

Line 4: If not used to complete line 3, this line is skipped.

Line 5, 6, and 7: These lines are used for pin assignments. All 20 of the pins on the PAL are assigned symbolic names, usually corresponding to the symbols used on the logic diagram. (Note that GND and V_{CC} must be included.) Assignment starts at pin 1 and proceeds sequentially, through pin 20. (See Figure 3-24 for sample pinouts.)

Line 8: Beginning on line 8, the logic equations that describe the required functions are written using the symbols defined in lines 5, 6, and 7, in the format applicable to the PAL selected. For example, the output of the 12L6 is low for the selected product term; therefore, the logic equations must be of the form $/O_x = f(I_1, I_2, \dots)$. The symbology used must be that shown in Figure 3-27.

```

Line 1   PAL 12L6   PAL Design Specification
Line 2   PAT 1476   Bob Jones 5/10/81
Line 3   PAL Design Example
Line 4
Line 5   I1 I2 I3 I4 I5 I6 I7 I8 I9 GND I10 NC O5
Line 6   O6 O4 O3 O2 O1 NC Vcc.
Line 7
Line 8   /O1 = I1
Line 9   /O2 = I1 + I2
Line 10  /O3 = I1 * I3
Line 11  /O4 = I3 * I4
Line 12  /O6 = I8 * I9 + I9 + I3 * I7 * I9 * I10
Line 13  /O5 = I3 * I5 * I6 + I7 + I8 * I9
Line 14
Line 15  Description
Line 16
Line 17  This program is a design example describing
Line 18  the use of PALASM as a PAL design aid.

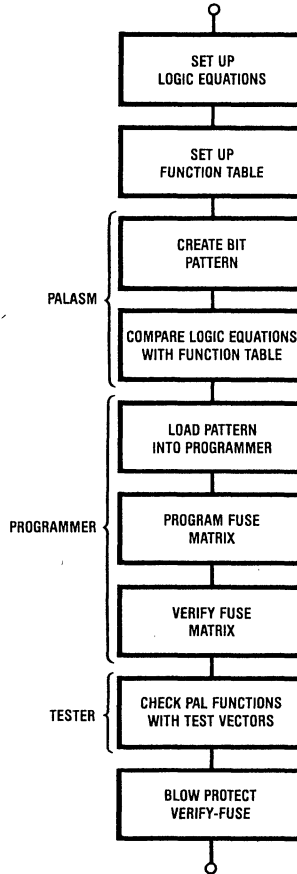
```

An additional design example using PALASM is shown on page 24-46. This is followed by the complete PALASM listing.

FIGURE 3-28. Example of PALASM (TM) Program Input

PAL Programming Procedure

The entire procedure for programming a PAL is shown in the block diagram below. The first step is to generate the logic equations and function table and then, using PALASM, to create bit pattern and compare logic equations with the function table. The third step is to load the bit pattern into a PAL programmer* to program and verify the fuse matrix. The fourth step is functionally testing the PAL with test vectors on a functional tester. The last step, blowing the protect verify fuse, is optional.



* See next page for details of PAL programmers.

PAL Programmers

Manufacturer	Basic Equipment	PAL-Modul	Adapters	PAL Design-Software Included	Performs Logic Simulation	Storage Media for		Programs		Blows Security Fuses
						Bit Pattern	Test Vectors	20-Pin	24-Pin	
Data I/O	Model 17, 19, 29A or 100A	1427	1428-1 -2 -3	no	no	Master PAL	—	yes	no	no
Digelec	μP 803	FAM 51	20 + 24 pin socket	yes	no	Master PAL	—	yes	yes	yes
Kontron	EPP 80 or MPP 80S	MOD 21	SA 27 + SA 27 - 1	no	no	Master PAL	—	yes	yes	yes
Prolog	Progr. 910 or 980 or NSC Starplex™	PM9068	S 1 2 3	no	no	Master PAL	—	yes	no	yes
Stag	PPX	PM 202 + BRAL	AM10H8 • • • AM16C1	yes	no	Master PAL	—	yes	no	yes

All these systems program and verify the PALs in the PROM mode, they *do not perform a logic simulation* in the PAL mode 1. Additional (external) circuitry for logic simulation should be used if PALs go into volume production—otherwise a small percentage of the PALs will show failures when testing the complete PC board! OK for prototype-making.

PAL Development Systems

Manufacturer	Basic Equipment	PAL-Modul	Adapters	PAL Design-Software Included	Performs Logic Simulation	Storage Media for		Programs		Blows Security Fuses
						Bit Pattern	Test Vectors	20-Pin	24-Pin	
Data I/O	Model 17, 19, 29A or 100 and any terminal	Logic-Pack	Design ad. and Progr. ad	yes	Yes, automatic or manual generation of test vectors	Master PAL	external	yes	yes	yes
Digelec	μP 803	FAM 52	20 and 24-pin adapter	yes	Yes, automatic or manual generation of test vectors	Master PAL	external	yes	yes	yes
Stag	—	ZL 30	—	yes	Yes, automatic or manual generation of test vectors	Master PAL	external	yes	yes	yes
Structured Design	any terminal	SD20/24	—	yes	Yes, manual generation of test vectors	Master PAL or on wafer tape	external or internal	yes	yes	no

All these systems allow software supported PAL design. They perform a *fuse-verify* in the PROM mode and can do a *logic simulation* in the PAL mode! All 5 programmers and 4 development systems can be connected with a host computer to run more sophisticated design software and/or for storage use.

PAL Legend

Constants

LOW (L)	NEGATIVE (N)	ZERO (0)	GND	FALSE	×		FUSE NOT BLOWN
HIGH (H)	POSITIVE (P)	ONE (1)	VCC	TRUE	-		FUSE BLOWN

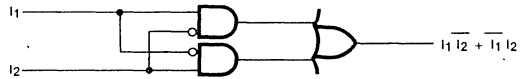
Operators

- = EQUAL
- := REPLACED BY FOLLOWING CLOCK
- / COMPLEMENT
- * AND, PRODUCT
- + OR, SUM
- +: XOR
- *: XNOR
- () CONDITIONAL THREE STATE, IF STATEMENT, ARITHMETIC

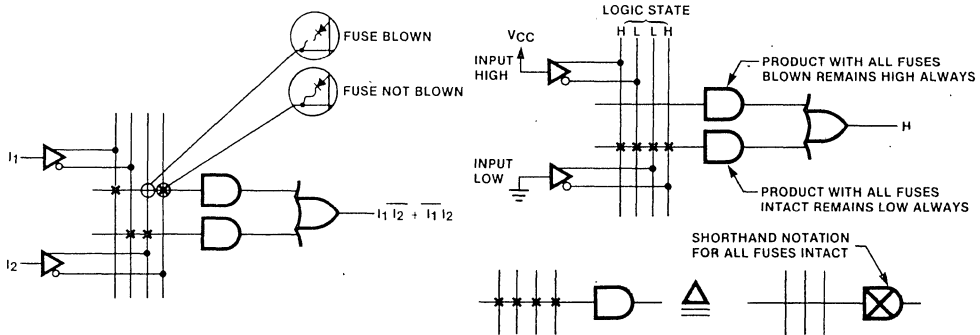
Equations

Standard	$Q_1 = I_1 \bar{I}_2 + \bar{I}_1 I_2$
PALASM	$Q1 = I1*/I2 + /I1*I2$

Conventional Symbology



PAL Symbology



PAL Logic Diagram

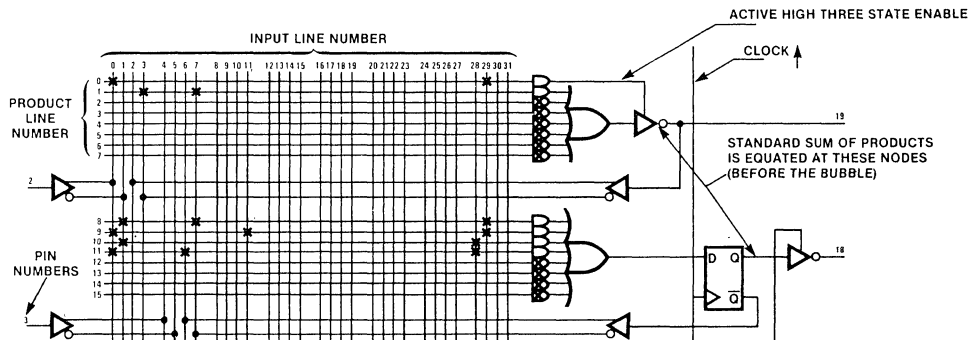


FIGURE 3-29. PAL Legend

Sample PAL Design Specification

PAL PART NO. (MUST START AT LINE 1, COLUMN 1)
 PATTERN NO.
 NAME OF DEVICE (MUST START ON LINE 3)
 PAL DESIGN SPECIFICATION
 AUTHOR'S NAME, DATE
 NAME OF DEVICE (EG. CLOCK GENERATOR, PORT ADDRESS DECODER, ETC)

PIN1 PIN2 3 /4 5 6 7 8 9 GND 11 12 13 /14 15 16 /17
 18 19 VCC

PIN LIST (MUST START ON LINE 5)
 CONSISTS OF 20 SYMBOLIC NAMES WHICH
 ARE CONSECUTIVELY ASSIGNED TO
 PINS 1 THRU 20.

19 = PIN1*4 + /PIN2
 18 = 5 + 6 + 7 + /8 + 9*11
 /17 := 8*9
 16 = 9*8
 IF (PIN1*PIN2) 15 = 3 + 6
 /14 = 3 + 6
 IF (VCC) 13 = 8*7 + PIN2

} EQUATIONS

CONDITIONAL THREE STATE

PALASM STOPS COMPILING AT FIRST UNDEFINED SYMBOL

FUNCTION TABLE

PIN1	PIN2	7	8	9	12	13	14	15	16	17	18	19
H	L	X	L	L	H	H	L	H	L	H	H	L ; CLEAR
.
.
.
.

FIGURE 3-30. Sample PAL Design Specification.

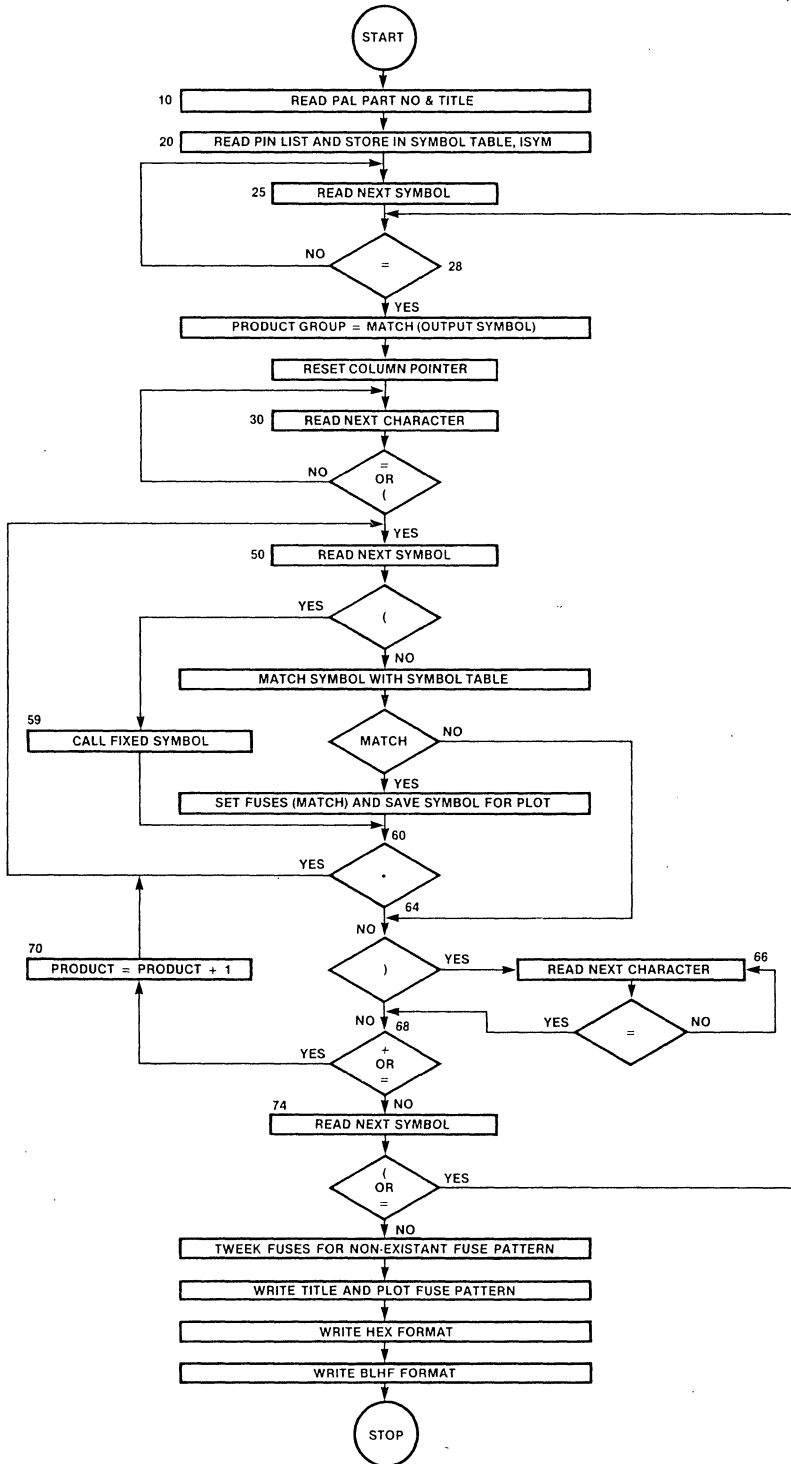


FIGURE 3-31. PALASM™ Flow Chart.

Listing 1. PALASM Source Code for 20 Series

FILE: PAL20 FORTRAN A NSC TIME SHARING SERVICES VM/SP RELEASE 2.0

```

C***PALASM20**PALASM20**PALASM20**PALASM20**PALASM20**PALASM20**PALASM20PAL00010
C PALASM 20 - TRANSLATES SYMBOLIC EQUATIONS INTO PAL OBJECT PAL00020
C CODE FORMATTED FOR DIRECT INPUT TO STANDARD PAL00030
C PROM PROGRAMMERS. PAL00040
C PAL00050
C INPUT: PAL DESIGN SPECIFICATION ASSIGNED PAL00060
C TO RPD(1). OPERATION CODES ARE PAL00070
C ASSIGNED TO ROP(5). PAL00080
C PAL00090
C OUTPUT: ECHO, SIMULATION, AND FUSE PATTERN PAL00100
C ARE ASSIGNED TO POF(6). HEX AND PAL00110
C BINARY PROGRAMMING FORMATS ARE PAL00120
C ASSIGNED TO PDF(6). PROMPTS AND PAL00130
C ERROR MESSAGES ARE ASSIGNED TO PAL00140
C PMS(6). PAL00150
C PAL00160
C PART NUMBER: THE PAL PART NUMBER MUST APPEAR PAL00170
C IN COLUMN ONE OF LINE ONE. PAL00180
C PAL00190
C PIN LIST: 20 SYMBOLIC PIN NAMES MUST APPEAR PAL00200
C STARTING ON LINE FIVE. PAL00210
C PAL00220
C EQUATIONS: STARTING FIRST LINE AFTER THE PAL00230
C PIN LIST IN THE FOLLOWING FORMS: PAL00240
C PAL00250
C  $A = B * C + D$  PAL00260
C PAL00270
C  $A := B * C + D$  PAL00280
C PAL00290
C  $IF (A * B) C = D + E$  PAL00300
C PAL00310
C  $A2 := (A1 * B1) + /C$  PAL00320
C PAL00330
C ALL CHARACTERS FOLLOWING ';' ARE PAL00340
C IGNORED UNTIL THE NEXT LINE. PAL00350
C PAL00360
C BLANKS ARE IGNORED. PAL00370
C PAL00380
C OPERATORS: ( IN HIERARCHY OF EVALUATION ) PAL00390
C PAL00400
C ; COMMENT FOLLOWS PAL00410
C / COMPLEMENT PAL00420
C * AND (PRODUCT) PAL00430
C + OR (SUM) PAL00440
C ++ XOR (EXCLUSIVE OR) PAL00450
C :* XNOR (EXCLUSIVE NOR) PAL00460
C ( ) CONDITIONAL THREE-STATE PAL00470
C OR FIXED SYMBOL PAL00480
C = EQUALITY PAL00490
C := REPLACED BY (AFTER CLOCK) PAL00500
C PAL00510
C PAL00520
C FIXED SYMBOLS PAL00530
C FOR PAL16X4 PAL00540
C AND PAL16A4 PAL00550

```

```

C          ONLY:      (AN+BN)      WHERE N = 0,1,2,3      PAL00560
C                   (AN*BN)      FOR OUTPUT PINS      PAL00570
C                   (AN)         17,16,15,14, RESP      PAL00580
C                   (/AN+BN)     A IS OUTPUT1          PAL00590
C                   (/BN)        B IS INPUT             PAL00600
C                   (AN+*BN)     PAL00610
C                   (AN*/BN)     PAL00620
C                   (/AN+BN)     PAL00630
C                   (AN:*BN)     PAL00640
C                   (BN)         PAL00650
C                   (AN*BN)     PAL00660
C                   (/AN)       PAL00670
C                   (/AN*/BN)   PAL00680
C                   (/AN*BN)    PAL00690
C                   PAL00700
C          FUNCTION   L, H, X, Z, AND C ARE VALID      PAL00710
C          TABLE:   FUNCTION TABLE VECTOR ENTRIES.  PAL00720
C
C          REFERENCE: A COMPLETE USERS GUIDE TO      PAL00730
C                   DESIGNING WITH PALS USING PALASM  PAL00740
C                   IS PROVIDED IN THE MONOLITHIC    PAL00750
C                   MEMORIES PAL HANDBOOK.           PAL00760
C
C          SUBROUTINES: INITLZ, SETSYM, INCR, MATCH, FIXSYM, PAL00780
C                   IXLATE, ECHO, CAT, PINOUT, PLOT, TWEAK, PAL00800
C                   BINA, HEX, SLIP, FANTOM, IOCC2, IOCC4, PAL00810
C                   TEST, FIXTST                     PAL00820
C
C          REV LEVEL: 02/12/82 (VAX/VMS VERSION)      PAL00830
C                   09/14/82 (SA1/SA0 FAULT TESTING) PAL00840
C                   10/15/82 (JEDEC FORMAT)          PAL00850
C                   By: Imtiaz Bengali               PAL00860
C
C          AUTHORS:  JOHN BIRKNER AND VINCENT COLI   PAL00870
C                   MONOLITHIC MEMORIES INC.         PAL00880
C                   1165 EAST ARQUES AVENUE          PAL00890
C                   SUNNYVALE, CALIFORNIA 94043     PAL00900
C                   (408) 739-3535                   PAL00910
C
C          FINE PRINT: MONOLITHIC MEMORIES TAKES NO  PAL00920
C                   RESPONSIBILITY FOR THE OPERATION PAL00930
C                   OR MAINTENANCE OF THIS PROGRAM.  PAL00940
C                   THE SOURCE CODE AS PRINTED HERE  PAL00950
C                   PRODUCED THE OBJECT CODE OF THE  PAL00960
C                   EXAMPLES IN THE APPLICATIONS     PAL00970
C                   SECTION ON A VAX/VMS 11/78J      PAL00980
C                   COMPUTER AND A NATIONAL CSS IBM  PAL00990
C                   SYSTEM/370 FORTRAN IV (G).      PAL01000
C
C          ***** PAL01010
C          ***** PAL01020
C          ***** PAL01030
C          ***** PAL01040
C          ***** PAL01050
C          ***** PAL01060
C          ***** PAL01070
C          ***** PAL01080
C          ***** PAL01090
C          ***** PAL01100
    
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C      MAIN PROGRAM
C
      IMPLICIT INTEGER (A-Z)
      INTEGER IPAL(4), REST(73), PATNUM(60), TITLE(80), COMP(80),
1      ISYM(8,20), LBUF(8,20)
      LOGICAL LBLANK, LLEFT, LAND, LOR, LSLASH, LEQUAL, LRIGHT, L XOR, L XOR,
1      LFIX, LFIRST, LMATCH, LFUSES(32,64), LPHASE(20), LBUF(20),
2      LPROD(80), LSAME, LACT, LOPERR, LINP, LPRD, LERR, LSA11, LSA01
      INTEGER BEL
      COMMON LBLANK, LLEFT, LAND, LOR, LSLASH, LEQUAL, LRIGHT, L XOR, L XOR
      COMMON /PGE/ IPAGE(80,200)
      COMMON /LFUSES/LFUSES
      COMMON /LUNIT/ PMS, POF, PDF
      COMMON /FTEST/ IFUNCT, IDESC, IEND
      DATA E/'E', O/'O', T/'T', P/'P', B/'B', H/'H', S/'S', L/'L',
1      N/'N', C/'C', Q/'Q', U/'U', F/'F', R/'R', A/'A', I/'I',
2      J/'J'
      DATA BB/'B', CC/'C', DD/'D', EE/'E', FF/'F', II/'I', JJ/'J',
1      NN/'N', OO/'O', PP/'P', RR/'R', SS/'S', TT/'T', UU/'U'
      DATA BEL/Z07000000/
C
C      ASSIGNMENT OF DATA SET REFERENCES
C      RPD - PAL DESIGN SPECIFICATION (INPUT)
C      ROC - OPERATION CODE (INPUT)
C      POF - ECHO, PINOUT, TEST, AND PLOT (OUTPUT)
C      PDF - HEX AND BINARY FORMAT PROGRAM TAPES (OUTPUT)
C      PMS - PROMPTS AND ERROR MESSAGES (OUTPJT)
      WRITE(6,3)
3      FORMAT(/, ' PALASM VERSION 1.5')
      WRITE(6,1)
1      FORMAT(/, ' WHAT IS THE LOGICAL UNIT NUMBER FOR OUTPUT(6)?: ')
      READ(5,2) LUN
2      FORMAT(I4)
      RPD=1
      ROC=5
      POF=6
      PDF=6
      PMS=10
      IFUNCT=0
      IDESC=0
C      INITIALIZE LSAME AND LACT TO FALSE (ACTIVE HIGH/LOW ERROR)
      LSAME=.FALSE.
      LACT=.FALSE.
C      INITIALIZE LOPERR TO FALSE (OUTPUT PIN ERROR)
      LOPERR=.FALSE.
C      INITIALIZE LINP TO FALSE (INPUT PIN ERROR)
      LINP=.FALSE.
C      INITIALIZE LPRD TO FALSE (PRODUCT LINE ERROR)
      LPRD=.FALSE.
C      READ IN FIRST 4 LINES OF THE PAL DESIGN SPECIFICATION
      READ(RPD,10) IPAL, INOAI, IOT, INOO, REST, PATNUM, TITLE, COMP
10     FORMAT(4A1, A1, A1, A1, 73A1, /, 80A1, /, 80A1, /, 80A1)
C      READ IN PIN LIST (LINE 5) THROUGH THE END OF THE PAL DESIGN
C      SPECIFICATION

```

PAL01110
PAL01120
PAL01130
PAL01140
PAL01150
PAL01160
PAL01170
PAL01180
PAL01190
PAL01200
PAL01210
PAL01220
PAL01230
PAL01240
PAL01250
PAL01260
PAL01270
PAL01280
PAL01290
PAL01300
PAL01310
PAL01320
PAL01330
PAL01340
PAL01350
PAL01360
PAL01370
PAL01380
PAL01390
PAL01400
PAL01410
PAL01420
PAL01430
PAL01440
PAL01450
PAL01460
PAL01470
PAL01480
PAL01490
PAL01500
PAL01510
PAL01520
PAL01530
PAL01540
PAL01550
PAL01560
PAL01570
PAL01580
PAL01590
PAL01600
PAL01610
PAL01620
PAL01630
PAL01640
PAL01650

```

DO 15 J=1,200
  READ(RPD,11,END=16) (IPAGE(I,J),I=1,80)
  11  FORMAT(30A1)
C    CHECK FOR 'FUNCTION TABLE' AND SAVE ITS LINE NUMBER
  IF(
  1    IFUNCT.EQ.0 .AND. IPAGE(1,J).EQ.FF.AND.
  2    IPAGE(2,J).EQ.UU.AND. IPAGE(3,J).EQ.NN.AND.
  3    IPAGE(4,J).EQ.CC.AND. IPAGE(5,J).EQ.TT.AND.
  4    IPAGE(6,J).EQ.II.AND. IPAGE(7,J).EQ.OO.AND.
  5    IPAGE(8,J).EQ.NN.AND. IPAGE(10,J).EQ.TT.AND.
  6    IPAGE(12,J).EQ.BB.AND. IPAGE(14,J).EQ.EE ) IFUNCT=J
C    CHECK FOR 'DESCRIPTION' AND SAVE ITS LINE NUMBER
  IF(
  1    IDESC.EQ.0 .AND. IPAGE(1,J).EQ.DD.AND.
  2    IPAGE(2,J).EQ.EE.AND. IPAGE(3,J).EQ.SS.AND.
  3    IPAGE(4,J).EQ.CC.AND. IPAGE(5,J).EQ.RR.AND.
  4    IPAGE(6,J).EQ.II.AND. IPAGE(7,J).EQ.PP.AND.
  5    IPAGE(8,J).EQ.TT.AND. IPAGE(9,J).EQ.II.AND.
  6    IPAGE(10,J).EQ.OO.AND. IPAGE(11,J).EQ.NN ) IDESC=J
  15 CONTINUE
C    SAVE THE LAST LINE NUMBER OF THE PAL DESIGN SPECIFICATION
  16 IEND=J-1
  CALL INITLZ(INOAI,IOT,INOO,ITYPE,LFUSES,IC,IL,IBLOW,LFIX,IPCTR)
  ILE=IL+1
C    PRINT ERROR MESSAGE FOR INVALID PAL PART TYPE
  IF(ITYPE.NE.0) GO TO 17
  WRITE(PMS,18) IPAL,INOAI,IOT,INOO
  18  FORMAT(/,' PAL PART TYPE ',4A1,A1,A1,A1,' IS INCORRECT')
  STOP
C    GET 20 PIN NAMES
  17 DO 20 J=1,20
  20  CALL GETSYM(LPHASE,ISYM,J,IC,IL,LFIX)
  IF(.NOT.(LEQUAL.OR.LLEFT.OR.LAND.OR.LOR.OR.LRIGHT)) GO TO 24
  WRITE(PMS,23)
  23  FORMAT(/,' LESS THAN 20 PIN NAMES IN PIN LIST')
  STOP
  24 ILE=IL
C    BYPASS FUSE PLOT ASSEMBLY IF HAL (H IN COLUMN 1, LINE 1)
  IF( IPAL(1).EQ.H ) GO TO 108
  25 CALL GETSYM(LBUF,IBUF,1,IC,IL,LFIX)
  28  IF(.NOT.LEQUAL) GO TO 25
  COUNT=0
  ILL=IL
  CALL MATCH(IMATCH,IBUF,ISYM)
  IF( IMATCH.EQ.0 ) GO TO 100
  IPRD=IMATCH
C    CHECK FOR VALID POLARITY
  LSAME = ( ( LPHASE(IMATCH) ) .AND. ( LBUF(1) ) .OR.
  1    ( .NOT.LPHASE(IMATCH) ) .AND. ( .NOT.LBUF(1) ) )
  IF( IOT.EQ.H.AND.(.NOT.LSAME) ) LACT=.TRUE.
  IF( (.NOT.(IOT.EQ.H.OR.IOT.EQ.C)) .AND.(LSAME) ) LACT=.TRUE.
C    CHECK FOR VALID OUTPUT PIN
  IF( (ITYPE.EQ.1.OR.ITYPE.EQ.5.OR.ITYPE.EQ.6) .AND. IOT.NE.A.
  1  AND. (IMATCH.LT.12.OR.IMATCH.GT.19) ) LOPERR=.TRUE.
  IF( ITYPE.EQ.2.AND. (IMATCH.LT.13.OR.IMATCH.GT.18) )
  1  LOPERR=.TRUE.
  IF( ITYPE.EQ.3.AND. (IMATCH.LT.14.OR.IMATCH.GT.17) )
  1  LOPERR=.TRUE.

```

PALO1660
PALO1670
PALO1680
PALO1690
PALO1700
PALO1710
PALO1720
PALO1730
PALO1740
PALO1750
PALO1760
PALO1770
PALO1780
PALO1790
PALO1800
PALO1810
PALO1820
PALO1830
PALO1840
PALO1850
PALO1860
PALO1870
PALO1880
PALO1890
PALO1900
PALO1910
PALO1920
PALO1930
PALO1940
PALO1950
PALO1960
PALO1970
PALO1980
PALO1990
PALO2000
PALO2010
PALO2020
PALO2030
PALO2040
PALO2050
PALO2060
PALO2070
PALO2080
PALO2090
PALO2100
PALO2110
PALO2120
PALO2130
PALO2140
PALO2150
PALO2160
PALO2170
PALO2180
PALO2190
PALO2200


```

1          LOPERR=.TRUE.          PAL02210
IF( ITYPE.EQ.4.AND.(IMATCH.LT.15.OR.IMATCH.GT.16) ) PAL02220
1          LOPERR=.TRUE.          PAL02230
IF( (LACT).OR.(LOPERR) ) GO TO 100 PAL02240
188PRO=(19-IMATCH)*3 + 1          PAL02250
C START PAL16C1 ON PRODUCT LINE 24 (188PRO=25) PAL02260
IF(IOT.EQ.C) 188PRO=25          PAL02270
IC=0          PAL02280
30 CALL INCR(IC,IL,LFIX)          PAL02290
IF( .NOT.(LEQUAL.OR.LLEFT) ) GO TO 30 PAL02300
LPROD(188PRO)=.TRUE.          PAL02310
IF( (.NOT.LLEFT).AND.(REST(3).NE.PP) ) CALL SLIP(LFUSES, PAL02320
1 188PRO,INOAI,IOT,IBLOW,IBLOW) PAL02330
DO 70 188PRO=1,16          PAL02340
COUNT = COUNT + 1          PAL02350
IF( (LXOR).AND.188PRO.NE.5 ) GO TO 70 PAL02360
IPROD = 188PRO + 188PRO - 1          PAL02370
LPROD(IPROD)=.TRUE.          PAL02380
LFIRST=.TRUE.          PAL02390
50 ILL=IL          PAL02400
CALL GETSYM(LBUF,IBUF,1,IC,IL,LFIX) PAL02410
IF( (ITYPE.EQ.1.OR.ITYPE.EQ.2.AND.IPRD.GT.13 PAL02420
1 .AND.IPRD.LT.18).AND.COUNT.GT.2 ) LPRD=.TRUE. PAL02430
IF( (ITYPE.EQ.3.OR.ITYPE.EQ.2.AND.(IPRD.EQ.13.OR. PAL02440
1 IPRD.EQ.18)).AND.COUNT.GT.4 ) LPRD=.TRUE. PAL02450
IF( IOT.NE.A.AND.IOT.NE.C.AND.COUNT.GT.8 ) LPRD=.TRUE. PAL02460
IF( .NOT.LPRD ) GO TO 69 PAL02470
IF(IL.NE.IFUNCT.AND.IL.NE.IDESC) ILL=IL PAL02480
IPROD = IPROD - 1          PAL02490
GO TO 118          PAL02500
69 IF(LFIX) GO TO 59          PAL02510
CALL MAICH(IMATCH,IBUF,ISYM) PAL02520
C CHECK FOR INVALID INPUT PIN          PAL02530
IF( ITYPE.EQ.1.AND.(IMATCH.GE.12.AND.IMATCH.LE.19) ) PAL02540
1 LINP=.TRUE.          PAL02550
IF( ITYPE.EQ.2.AND.(IMATCH.GE.13.AND.IMATCH.LE.18) ) PAL02560
1 LINP=.TRUE.          PAL02570
IF( ITYPE.EQ.3.AND.(IMATCH.GE.14.AND.IMATCH.LE.17) ) PAL02580
1 LINP=.TRUE.          PAL02590
IF( ITYPE.EQ.4.AND.(IMATCH.EQ.15.OR.IMATCH.EQ.16) ) PAL02600
1 LINP=.TRUE.          PAL02610
IF( ITYPE.EQ.5.AND.(IMATCH.EQ.12.OR.IMATCH.EQ.19) ) PAL02620
1 LINP=.TRUE.          PAL02630
IF( ITYPE.EQ.6.AND.(IMATCH.EQ.1.OR.IMATCH.EQ.11) ) PAL02640
1 LINP=.TRUE.          PAL02650
ILL=IL          PAL02660
IF(LINP) GO TO 100          PAL02670
IF( IMATCH.EQ.0 ) GO TO 100          PAL02680
IF( IMATCH.EQ.10.OR.IMATCH.EQ.99 ) GO TO 64 PAL02690
IF(.NOT.LFIRST) GO TO 58          PAL02700
LFIRST=.FALSE.          PAL02710
DO 56 I=1,32          PAL02720
IBLOW = IBLOW + 1          PAL02730
56 LFUSES(I,IPROD)=.TRUE.          PAL02740
58 CALL XLATE(IINPUT,IMATCH,LPHASE,LBUF,ITYPE) PAL02750

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```

IF(IINPUT.LE.0) GO TO 60
IBLOW = IBLOW - 1
LFUSES (IIMPJT,IPROD)=.FALSE.
CALL PLOT (LBUF,IBUF,LFUSES,IPROD,TITLE,.FALSE.,ITYPE,
          LPR3D,IOP,IBLOW,IPCTR)
1
GO TO 60
59 CALL FXIASYM(LBUF,IBUF,IC,IL,LFIRST,LFUSES,IBLOW,
          IPROD,LFIX)
60 IF(LAND) GO TO 60
64 IF(.NOT.LHIGHT) GO TO 68
66 CALL INCR(IC,IL,LFIX)
IF(.NOT.LEQUAL) GO TO 66
68 IF(.NOT.(LOR.OR.LEQUAL)) GO TO 74
70 CONTINUE
74 ILL=IL
CALL GETSYM(LBUF,IBUF,I,IC,IL,LFIX)
IF(LLEFT.OR.LEQUAL) GO TO 28
100 IF( ILL.E2.IFUNCT.OR.ILL.E2.IDESC ) GO TO 102
C PRINT AN ERROR MESSAGE IF UNRECOGNIZABLE SYMBOL
ILERR=ILL*4
WRITE(PMS,99) BEL
99 FORMAT(' ',A1)
WRITE(PMS,101) (IBUF(I,I),I=1,6),ILERR,(IPAGE(I,ILL),I=1,60)
101 FORMAT(/,' ERROR SYMBOL = ',8A1,' IN LINE NUMBER ',I3,
          /,' ',30A1)
C PRINT AN ERROR MESSAGE FOR ACTIVE HIGH/LOW PART
IF( (LACT).AND.( LSAME).AND.(.NOT.LOPERR) )
1 WRITE(PMS,103) IPAL,INOAI,IOT,INOO
103 FORMAT(' OUTPUT MUST BE INVERTED SINCE ',4A1,A1,A1,A1,
          ' IS AN ACTIVE LOW DEVICE')
IF( (LACT).AND.(.NOT.LSAME).AND.(.NOT.LOPERR) )
1 WRITE(PMS,109) IPAL,INOAI,IOT,INOO
109 FORMAT(' OUTPUT CANNOT BE INVERTED SINCE ',4A1,A1,A1,A1,
          ' IS AN ACTIVE HIGH DEVICE')
C PRINT AN ERROR MESSAGE FOR AN INVALID OUTPUT PIN
IF( (LOPERR).AND.IMATCH.NE.0 )
1 WRITE(PMS,105) IMATCH,IPAL,INOAI,IOT,INOO
105 FORMAT(' THIS PIN NUMBER ',I2,' IS AN INVALID OUTPUT PIN',
          ' FOR ',4A1,A1,A1,A1)
C PRINT AN ERROR MESSAGE FOR AN INVALID INPUT PIN
IF(LINP) WRITE(PMS,115) IMATCH,IPAL,INOAI,IOT,INOO
115 FORMAT(' THIS PIN NUMBER ',I2,' IS AN INVALID INPUT PIN',
          ' FOR ',4A1,A1,A1,A1)
C PRINT AN ERROR MESSAGE FOR INVALID PRODUCT LINE
118 ILERR=ILL*4
IF(LPRD) WRITE(PMS,119)
1 (ISYM(I,IPRD),I=1,8),IPRD,ILERR,(IPAGE(I,ILL),I=1,60)
119 FORMAT(/,' OUTPUT PIN NAME = ',8A1,' OUTPUT PIN NUMBER = ',I2,
          /,' MINTERM IN LINE NUMBER ',I3,/,' ',30A1)
IF( LPRD.AND.COUNT.LF.3 )
1 WRITE(PMS,116) IPROD,IPAL,INOAI,IOT,INOO
116 FORMAT(' THIS PRODUCT LINE NUMBER ',I2,' IS NOT VALID',
          ' FOR ',4A1,A1,A1,A1)
IF( LPRD.AND.COUNT.ST.8 )
1 WRITE(PMS,117) IPAL,INOAI,IOT,INOO

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PAL02760
PAL02770
PAL02780
PAL02790
PAL02800
PAL02810
PAL02820
PAL02830
PAL02840
PAL02850
PAL02860
PAL02870
PAL02880
PAL02890
PAL02900
PAL02910
PAL02920
PAL02930
PAL02940
PAL02950
PAL02960
PAL02970
PAL02980
PAL02990
PAL03000
PAL03010
PAL03020
PAL03030
PAL03040
PAL03050
PAL03060
PAL03070
PAL03080
PAL03090
PAL03100
PAL03110
PAL03120
PAL03130
PAL03140
PAL03150
PAL03160
PAL03170
PAL03180
PAL03190
PAL03200
PAL03210
PAL03220
PAL03230
PAL03240
PAL03250
PAL03260
PAL03270
PAL03280
PAL03290
PAL03300

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117 FORMAT(' MAXIUM OF 8 PRODUCT LINES ARE VALID FOR ',4A1,A1,A1,A1, PAL03310
1      /,' TOO MANY NINTERMS ARE SPECIFIED IN THIS EQUATION') PAL03320
      STOP PAL03330
102 IF (ITYPE,LE,4) CALL TWEAK (ITYPE,IOT,LFUSES) PAL03340
108 WRITE (6,106) PAL03350
106 FORMAT(/,' OPERATION CODES:') PAL03360
      WRITE (6,107) PAL03370
107 FORMAT(/,' E=ECHO INPUT O=PINOUT T=SIMULATE P=PLOT B=BRIEF', PAL03380
1      /,' H=HEX S=SHORT L=BHLF N=BNPF C=CATALOG Q=QUIT', PAL03390
2      /,' F=FAULT TESTING J=JEDEC FORMAT') PAL03400
      WRITE (6,110) PAL03410
110 FORMAT(/,' ENTER OPERATION CODE: ') PAL03420
      READ (ROC,120) IOP PAL03430
120 FORMAT(A1) PAL03440
C      CALL IODC2 PAL03450
      IF (POF,NE,6) WRITE (POF,125) PAL03460
125 FORMAT('1') PAL03470
      IF (IOP,EQ,E) CALL ECHO (IPAL,INOAI,IOT,INOO,REST,PATNUM,TITLE,
1          COMP) PAL03480
      IF (IOP,EQ,O) CALL PINOUT (IPAL,INOAI,IOT,INOO,TITLE) PAL03500
      IF (IOP,EQ,T) CALL TEST (LPHASE,LBUF,TITLE,IC,IL,ILE,ISYM,IBUF,
1          ITYPE,INOO,LFIX,IPCTR,LERR,ISAF,IPCTR1,
2          .FALSE,..FALSE.) PAL03520
C      INITIALIZING THE TOTAL FAULTS. CALLING FOR SA1/SAO TEST PAL03540
      ISAF=0 PAL03550
      IF (IOP,EQ,F) GO TO 200 PAL03560
      IF (IOP,EQ,JJ) CALL PLOT F PAL03570
135 IF (IOP,EQ,P) CALL PLOT (LBUF,IBUF,LFUSES,IPROD,TITLE,.TRUE.,ITYPE, PAL03580
1          LPROD,IOP,IBLOW,IPCTRO) PAL03590
      IF (IOP,EQ,B) CALL PLOT (LBUF,IBUF,LFUSES,IPROD,TITLE,.TRUE.,ITYPE, PAL03600
1          LPROD,IOP,IBLOW,IPCTRO) PAL03610
      IF (IOP,EQ,H) CALL HEX (LFUSES,H) PAL03620
      IF (IOP,EQ,S) CALL HEX (LFUSES,S) PAL03630
      IF (IOP,EQ,L) CALL BINR (LFUSES,H,L) PAL03640
      IF (IOP,EQ,N) CALL BINR (LFUSES,P,N) PAL03650
      IF (IOP,EQ,C) CALL CAT PAL03660
C      CALL IODC4 PAL03670
      IF (IOP,NE,Q) GO TO 108 PAL03680
      STOP PAL03690
C      PAL03700
C      SETTING THE PARAMETERS FOR SA1/SAO TESTS PAL03710
200 IPCTR=0 PAL03720
      CALL TEST (LPHASE,LBUF,TITLE,IC,IL,ILE,ISYM,IBUF,ITYPE,
1          INOO,IFIX,IPCTR,LERR,ISAF,IPCTR1,.FALSE,..FALSE.) PAL03730
      IPCTRO=IPCTR PAL03740
C      LOOPING FOR SA1 TEST PAL03750
      DO 210 IPCTR1=1,IPCTRO PAL03760
      LSA11=.TRUE. PAL03770
      CALL TEST (LPHASE,LBUF,TITLE,IC,IL,ILE,ISYM,IBUF,ITYPE,
1          INOO,IFIX,IPCTR,LERR,ISAF,IPCTR1,LSA11,.FALSE.) PAL03780
210 CONTINUE PAL03790
      LSA1=ISAF PAL03800
C      LOOPING FOR SAO TEST PAL03810
      DO 215 IPCTR1=1,IPCTRO PAL03820
      LSA01=.TRUE. PAL03830
      PAL03840
      PAL03850

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```

CALL TEST(LPHASE, LBUF, TITLE, IC, IL, ILE, ISYM, IBUF, ITYPE,
1      INOO, IFLX, IPCR, LERR, ISAF, IPCR1, .FALSE., LSAC1)
215 CONTINUE
ISAO=ISAF-ISA1
IFAULT=(LSAF*100)/(IPCTR*2)
WRITE(POF,220) ISA1
220 FORMAT(/, ' NUMBER OF STUCK AT ONE (SA1) FAULTS ARE =' I3)
WRITE(POF,225) ISAO
225 FORMAT(/, ' NUMBER OF STUCK AT ZERO (SA0) FAULTS ARE =' I3)
WRITE(POF,230) IFAULT
230 FORMAT(/, ' PRODUCT TERM COVERAGE          =' I3, '%', '/')
GO TO 135

C
END

C
C *****THIS SUBROUTINE IS ADDED FOR JEDEC FORMAT*****
C THE FOLLOWING SUBROUTINE GIVES JEDEC FORMATTED OUTPUT FOR
C PROGRAMMING COMPATIBILITY WITH DATA I/O PROGRAMMERS
SUBROUTINE PLOTF
IMPLICIT INTEGER (A-Z)
LOGICAL LFUSES (32,64)
INTEGER IPBUF (32), ZERO, ONE
INTEGER ISUM (4), IADR, STX, ETX, IDEC (4), IPT, IINP, J1, J2
INTEGER IDECIO (4), ISUMV (4), ISUMIG (4), BUFLIO (32)
COMMON /LUNIT/ PMS, POF, PDF
COMMON /LPT/ IPT
COMMON /LFUSES/ LFUSES
COMMON /SUM/ ISUM, IADR, IPBUF, BUFLIO
DATA ZERO/'0', ONE/'1'/
IADR=0
STX=2
ETX=3
ISUM(2)=0
ISUM(4)=230
WRITE(PDF,10) STX
10 FORMAT(' ', A1, ' *FO*')
DO 300 IPT=1,64
DO 50 IINP=1,32
IF(LFUSES(IINP, IPT)) IPBUF(IINP)=ONE
IF(.NOT.(LFUSES(IINP, IPT))) IPBUF(IINP)=ZERO
50 CONTINUE
IF(LFUSES(1, IPT)) GO TO 100
IF(.NOT.LFUSES(2, IPT)) GO TO 250
100 IDEC(4)=IADR
DO 150 J=1,3
J1=5-J
J2=4-J
IDEC(J2)=IDEC(J1)/10
IDEC(J1)=IDEC(J1)-10*IDEC(J2)
IDECIO(J1)=ICONV(IDEC(J1))
150 CONTINUE
IDECIO(1)=ICONV(IDEC(1))
CALL SUMCHK
WRITE(PDF,201) IDECIO, IPBUF
201 FORMAT(' L', 4A1, ' ', 3(4A1, ' '), ' *')

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PAL03860
PAL03870
PAL03880
PAL03890
PAL03900
PAL03910
PAL03920
PAL03930
PAL03940
PAL03950
PAL03960
PAL03970
PAL03980
PAL03990
PAL04000
PAL04010
PAL04020
PAL04030
PAL04040
PAL04050
PAL04060
PAL04070
PAL04080
PAL04090
PAL04100
PAL04110
PAL04120
PAL04130
PAL04140
PAL04150
PAL04160
PAL04170
PAL04180
PAL04190
PAL04200
PAL04210
PAL04220
PAL04230
PAL04240
PAL04250
PAL04260
PAL04270
PAL04280
PAL04290
PAL04300
PAL04310
PAL04320
PAL04330
PAL04340
PAL04350
PAL04360
PAL04370
PAL04380
PAL04390
PAL04400

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250 IADR=IADR+32
300 CONTINUE
    ISUMIO(1)=ICONV(ISUM(2)/16)
    ISUM(2)=MOD(ISUM(2),16)
    ISUMIO(2)=ICONV(ISUM(2))
    ISUMIO(3)=ICONV(ISUM(4)/16)
    ISUM(4)=MOD(ISUM(4),16)
    ISUMIO(4)=ICONV(ISUM(4))
    WRITE(PDF,400) ETX,ISUMIO
400 FORMAT(' *',A1,4A1,'*',/)
    RETURN
    END
C
C*****
C
C THIS SUBROUTINE CALCULATES THE SUMCHECK
SUBROUTINE SUMCHK
IMPLICIT INTEGER (A-Z)
LOGICAL LFUSES(32,64)
INTEGER IPBUF(32), BUFIO(32)
INTEGER ISUM(4), IDEC(4)
COMMON /IPT/ IPT
COMMON /LFUSES/ LFUSES
COMMON/SUM/ ISUM, IDEC, IPBUF, BUFIO
DO 50 J=1, 32
IF(LFUSES(J, IPT)) BUFIO(J)=49
IF(.NOT.LFUSES(J, IPT)) BUFIO(J)=48
ISUM(4)=ISUM(4)+BUFIO(J)
IF(ISUM(4).GE.256) ISUM(2)=ISUM(2)+1
ISUM(4)=MOD(ISUM(4), 256)
50 CONTINUE
DO 100 J=1, 4
ISUM(4)=ISUM(4)+IDEC(J)+48
IF(ISUM(4).GE.256) ISUM(2)=ISUM(2)+1
ISUM(4)=MOD(ISUM(4), 256)
100 CONTINUE
ISUM(4)=ISUM(4)+173
ISUM(2)=ISUM(2)+1
IF(ISUM(4).GE.256) ISUM(2)=ISUM(2)+1
ISUM(4)=MOD(ISUM(4), 256)
RETURN
END
C*****
C
C
INTEGER FUNCTION ICONV(K)
IMPLICIT INTEGER (A-Z)
DATA A/'0'/, B/'1'/, C/'2'/, D/'3'/, E/'4'/, F/'5'/, G/'6'/, H/'7'/
DATA I/'8'/, J/'9'/, X/'A'/, L/'B'/, M/'C'/, N/'D'/, O/'E'/, P/'F'/
IF(K.EQ.0) ICONV=A
IF(K.EQ.1) ICONV=B
IF(K.EQ.2) ICONV=C
IF(K.EQ.3) ICONV=D
IF(K.EQ.4) ICONV=E
IF(K.EQ.5) ICONV=F

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IF (K.EQ.6) ICONV=G PAL04960
IF (K.EQ.7) ICONV=H PAL04970
IF (K.EQ.8) ICONV=I PAL04980
IF (K.EQ.9) ICONV=J PAL04990
IF (K.EQ.10) ICONV=X PAL05000
IF (K.EQ.11) ICONV=L PAL05010
IF (K.EQ.12) ICONV=M PAL05020
IF (K.EQ.13) ICONV=N PAL05030
IF (K.EQ.14) ICONV=C PAL05040
IF (K.EQ.15) ICONV=P PAL05050
RETURN PAL05060
END PAL05070
C PAL05080
C PAL05090
C***** PAL05100
C SUBROUTINE INITLZ (INOAI, IOT, INOO, ITYPE, LFUSES, IC, IL, IBLW, LFIX, PAL05110
C | IPCTR) PAL05120
C THIS SUBROUTINE INITIALIZES VARIABLES AND MATCHES PAL PART PAL05130
C NUMBER WITH ITYPE PAL05140
C IMPLICIT INTEGER (A-Z) PAL05150
C LOGICAL LBLANK, LLEFT, LAND, LOR, LSLASH, LEQUAL, LRIGHT, Lxor, LxNOR, PAL05160
C | LFIX, LFUSES (32, 64) PAL05170
C COMMON LBLANK, LLEFT, LAND, LOR, LSLASH, LEQUAL, LRIGHT, Lxor, LxNOR PAL05180
C COMMON /PGE/ IPAGE (80, 200) PAL05190
C DATA H/'H'/, L/'L'/, C/'C'/, R/'R'/, X/'X'/, A/'A'/, PAL05200
C | 10/'0'/, I2/'2'/, I4/'4'/, I6/'6'/, I8/'8'/' PAL05210
C INITIALIZE LFUSES ARRAY (FUSE ARRAY) PAL05220
C DO 20 J=1, 64 PAL05230
C | DO 20 I=1, 32 PAL05240
C 20 LFUSES (I, J) = .FALSE. PAL05250
C INITIALIZE IBLW (NUMBER OF FUSES BLOWN) PAL05260
C IBLW=0 PAL05270
C INITIALIZE IPCTR (NUMBER OF PRODUCT TERMS) PAL05280
C IPCTR=0 PAL05290
C INITIALIZE IC AND IL (COLUMN AND LINE POINTERS) PAL05300
C IC=0 PAL05310
C IL=1 PAL05320
C INITIALIZE ITYPE (PAL PART TYPE) PAL05330
C ITYPE=0 PAL05340
C ITYPE IS ASSIGNED THE FOLLOWING VALUES FOR THESE PAL TYPES: PAL05350
C PAL10H6, PAL10L8 ITYPE=1 PAL05360
C PAL12H6, PAL12L6 ITYPE=2 PAL05370
C PAL14H4, PAL14L4 ITYPE=3 PAL05380
C PAL16H2, PAL16L2, PAL16C1 ITYPE=4 PAL05390
C PAL16L3 ITYPE=5 PAL05400
C PAL16R4, PAL16R6, PAL16R8, PAL16X4, PAL16A4 ITYPE=6 PAL05410
C DETERMINE ITYPE PAL05420
C IF ( INOAI.EQ.10 ) ITYPE=1 PAL05430
C IF ( INOAI.EQ.12 ) ITYPE=2 PAL05440
C IF ( INOAI.EQ.14 ) ITYPE=3 PAL05450
C IF ( (INOAI.EQ.16) ) ITYPE=4 PAL05460
C IF ( (INOAI.EQ.16) .AND. (INOO.EQ.16) ) ITYPE=5 PAL05470
C IF ( (IOT.EQ.R) .OR. (IOT.EQ.X) .OR. (IOT.EQ.A) ) ITYPE=6 PAL05480
C IF ( .NOT. (IOT.EQ.H.OR.IOT.EQ.L.OR.IOT.EQ.C) ) PAL05490

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1      .OR.IOT.EQ.R.OR.IOT.EQ.X.OR.IOT.EQ.A ) ITYPE=0      PAL05510
      CALL INCR(IC,IL,LFIX)      PAL05520
      RETURN      PAL05530
      END      PAL05540
C      PAL05550
C*****      PAL05560
C      PAL05570
      SUBROUTINE GETSYM(LPHASE,ISYM,J,IC,IL,LFIX)      PAL05580
C      THIS SUBROUTINE GETS THE PIN NAME, / IF COMPLEMENT LOGIC, AND      PAL05590
C      THE FOLLOWING OPERATION SYMBOL IF ANY      PAL05600
      IMPLICIT INTEGER (A-Z)      PAL05610
      INTEGER ISYM(8,20)      PAL05620
      LOGICAL LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LXNOR,      PAL05630
1      LFIX,LPHASE(20)      PAL05640
      COMMON LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LXNOR      PAL05650
      COMMON /PGE/ IPAGE(80,200)      PAL05660
      DATA IBLANK/' '/      PAL05670
      LFIX=.FALSE.      PAL05680
      IF( .NOT.(LLEFT.OR.LAND.OR.LOR.OR.LEQUAL.OR.LRIGHT) ) GO TO 10      PAL05690
      CALL INCR(IC,IL,LFIX)      PAL05700
      IF(LLEFT) GO TO 60      PAL05710
10     LPHASE(J)=( .NOT,LSLASH )      PAL05720
      IF(LPHASE(J)) GO TO 15      PAL05730
      CALL INCR(IC,IL,LFIX)      PAL05740
15     DO 20 I=1,8      PAL05750
20       ISYM(I,J)=IBLANK      PAL05760
25     DO 30 I=1,7      PAL05770
30       ISYM(I,J)=ISYM(I+1,J)      PAL05780
      ISYM(8,J)=IPAGE(IC,IL)      PAL05790
      CALL INCR(IC,IL,LFIX)      PAL05800
      IF( LLEFT.OR.LBLANK.OR.LAND.OR.LOR.OR.LRIGHT.OR.LEQUAL ) RETURN      PAL05810
      GO TO 25      PAL05820
60     LFIX=.TRUE.      PAL05830
      RETURN      PAL05840
      END      PAL05850
C      PAL05860
C*****      PAL05870
C      PAL05880
      SUBROUTINE INCR(IC,IL,LFIX)      PAL05890
C      THIS SUBROUTINE INCREMENTS COLUMN AND LINE POINTERS      PAL05900
C      BLANKS AND CHARACTERS AFTER ';' ARE IGNORED      PAL05910
      IMPLICIT INTEGER (A-Z)      PAL05920
      LOGICAL LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LXNOR,      PAL05930
1      LFIX,LX!      PAL05940
      COMMON LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LXNOR      PAL05950
      COMMON /PGE/ IPAGE(80,200)      PAL05960
      COMMON /LUNIT/ PMS,PDF,PDF      PAL05970
      DATA IBLANK/' ',ILEFT/' (',IAND/'*',IOR/'/',COMENT/';',      PAL05980
1      ISLASH/'/',IEQUAL/'=',IRIGHT/'/',ICOLON/'://'      PAL05990
      LBLANK=.FALSE.      PAL06000
      LXOR=.FALSE.      PAL06010
      LXNOR=.FALSE.      PAL06020
      LX!=.FALSE.      PAL06030
      LRIGHT=.FALSE.      PAL06040
10     IC=IC+1      PAL06050

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IF(IC .LE.79 .AND. IPAGE(IC,IL).NE.COMENT) GO TO 30          PAL06060
IL=IL+1                                                    PAL06070
IF(IL.LE.200) GO TO 20                                     PAL06080
WRITE(PMS,15)                                             PAL06090
15  FORMAT(/,' SOURCE FILE EXCEEDS 200 LINES OR MISSING',  PAL06100
1      ' DESCRIPTION OR FUNCTION TABLE KEY WORD')        PAL06110
STOP                                                       PAL06120
20 IC=0                                                    PAL06130
GO TO 10                                                  PAL06140
30 IF( IPAGE(IC,IL).EQ.ICOLON.AND.(LFX) ) RETURN         PAL06150
IF( IPAGE(IC,IL).NE.IBLANK ) GO TO 31                   PAL06160
LBLANK=.TRUE.                                           PAL06170
GO TO 10                                                  PAL06180
31 IF( IPAGE(IC,IL).NE.ICOLON ) GO TO 32                 PAL06190
IF( (LXOR).OR.(LXNOR) ) GO TO 33                       PAL06200
LX1=.TRUE.                                              PAL06210
GO TO 10                                                  PAL06220
33 IF(LXOR) LOR=.TRUE.                                    PAL06230
IF(LXNOR) LAND=.TRUE.                                   PAL06240
RETURN                                                  PAL06250
32 IF( .NOT.(LX1.AND.(IPAGE(IC,IL).EQ.IOR.OR.IPAGE(IC,IL).EQ.IAND) ) ) PAL06260
1      GO TO 34                                           PAL06270
IF( IPAGE(IC,IL).EQ.IOR ) LXOR=.TRUE.                  PAL06280
IF( IPAGE(IC,IL).EQ.IAND ) LXNOR=.TRUE.                PAL06290
GO TO 10                                                  PAL06300
34 LLEFT =( IPAGE(IC,IL).EQ.ILEFT )                     PAL06310
LAND =( IPAGE(IC,IL).EQ.IAND )                          PAL06320
LOR =( IPAGE(IC,IL).EQ.IOR )                             PAL06330
LSLASH=( IPAGE(IC,IL).EQ.ISLASH )                       PAL06340
LEQUAL=( IPAGE(IC,IL).EQ.IEQUAL )                       PAL06350
LRIGHT=( IPAGE(IC,IL).EQ.IRIGHT )                       PAL06360
RETURN                                                  PAL06370
END                                                       PAL06380
C                                                         PAL06390
C*****PAL06400
C                                                         PAL06410
SUBROUTINE MATCH(IMATCH,IBUF,ISYM)                       PAL06420
THIS SUBROUTINE FINDS A MATCH BETWEEN THE PIN NAME IN THE EQUATIONPAL06430
AND THE PIN NAME IN THE PIN LIST OR FUNCTION TABLE PIN LIST PAL06440
C IMPLICIT INTEGER (A-Z)                                  PAL06450
C INTEGER IBUF(8,20),ISYM(8,20)                          PAL06460
LOGICAL LMATCH                                           PAL06470
DATA C/'C'//,A/'A'//,R/'R'//,Y/'Y'//                  PAL06480
LMATCH=0                                                  PAL06490
DO 20 J=1,20                                             PAL06500
LMATCH=.TRUE.                                           PAL06510
DO 10 I=1,8                                             PAL06520
10  LMATCH=LMATCH.AND.(IBUF(I,1).EQ.ISYM(I,J))          PAL06530
IF(LMATCH) IMATCH=J                                     PAL06540
20  CONTINUE                                             PAL06550
C MATCH CARRY WHICH IS FOUND IN THE PAL16A4             PAL06560
IF( IBUF(3,1).EQ.C.AND.IBUF(4,1).EQ.A.AND.IBUF(5,1).EQ.R.AND. PAL06570
1  IBUF(6,1).EQ.R.AND.IBUF(7,1).EQ.Y ) IMATCH=99       PAL06580
RETURN                                                  PAL06590
END                                                       PAL06600

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C
C***** PAL06610
C***** PAL06620
C***** PAL06630
C      SUBROUTINE IXLATE(IINPUT,IMATCH,LPHASE,LBUF,ITYPE) PAL06640
C      THIS SUBROUTINE FINDS A MATCH BETWEEN THE INPUT PIN NUMBER AND PAL06650
C      THE INPUT LINE NUMBER FOR A SPECIFIC PAL.  ADD 1 TO THE INPUT PAL06660
C      LINE NUMBER IF THE PIN IS A COMPLEMENT PAL06670
C      IMPLICIT INTEGER (A-Z) PAL06680
C      INTEGER ITABLE(20,6) PAL06690
C      LOGICAL LPHASE(20),LBUF(20) PAL06700
C      DATA ITABLE/ PAL06710
1  3, 1, 5, 9,13,17,21,25,29,-10,31,-1,-1,-1,-1,-1,-1,-1,-1,-20, PAL06720
2  3, 1, 5, 9,13,17,21,25,29,-10,31,27,-1,-1,-1,-1,-1,-1, 7,-20, PAL06730
3  3, 1, 5, 9,13,17,21,25,29,-10,31,27,23,-1,-1,-1,-1,11, 7,-20, PAL06740
4  3, 1, 5, 9,13,17,21,25,29,-10,31,27,23,19,-1,-1,15,11, 7,-20, PAL06750
5  3, 1, 5, 9,13,17,21,25,29,-10,31,-1,27,23,19,15,11, 7,-1,-20, PAL06760
6 -1, 1, 5, 9,13,17,21,25,29,-10,-1,31,27,23,19,15,11, 7, 3,-20/ PAL06770
C      IINPUT=0 PAL06780
C      IBUBL=0 PAL06790
C      IF((( LPHASE(IMATCH)).AND.(.NOT,LBUF(1))).OR. PAL06800
1  ((.NOT,LPHASE(IMATCH)).AND.( LBUF(1)))) IBUBL=1 PAL06810
C      IF( ITABLE(IMATCH,ITYPE).GT.0 ) IINPUT=ITABLE(IMATCH,ITYPE)+IBUBL PAL06820
C      RETURN PAL06830
C      END PAL06840
C***** PAL06850
C***** PAL06860
C***** PAL06870
C      SUBROUTINE FIXSYM(LBUF,LBUF,IC,IL,LFIRST,LFUSES,IBLOW,IPROD,LFIX) PAL06880
C      THIS SUBROUTINE EVALUATES THE FIXED SYMBOLS FOUND IN THE PAL06890
C      PAL16X4 AND PAL16A4 PAL06900
C      IMPLICIT INTEGER (A-Z) PAL06910
C      LOGICAL LBUF(20),LFUSES(32,64),LFIRST,LMATCH,LFIX PAL06920
C      INTEGER IBUF(8,20),FIXBUF(8),TABLE(5,14) PAL06930
C      COMMON /PAGE/ IPAGE(80,200) PAL06940
C      DATA A/'A'/,B/'B'/,ISLASH/'/'/,IOR/'/'/,IBLANK/' '/,IRIGHT/'/'/, PAL06950
1  LAND/'&'/,N/'N'/,Q/'Q'/,NO/'O'/,N1/'1'/,N2/'2'/,N3/'3'/, PAL06960
2  ICOLON/':'/, PAL06970
3  TABLE / 'A','B','A','B','A','B','A','B', PAL06980
4  'A','B','A','B','A','B','A','B','A','B','A','B', PAL06990
5  'A','B','A','B','A','B','A','B','A','B','A','B', PAL07000
6  'A','B','A','B','A','B','A','B','A','B','A','B', PAL07010
7  'A','B','A','B','A','B','A','B','A','B','A','B', PAL07020
C      IINPUT=0 PAL07030
C      DO 20 I=1,6 PAL07040
C          IBUF(I,1)=IBLANK PAL07050
20  FIXBUF(I)=IBLANK PAL07060
C      21 CALL INCR(IC,IL,LFIX) PAL07070
C          I=IPAGE(IC,IL) PAL07080
C          IF(I.EQ.IRIGHT) GO TO 40 PAL07090
C          IF(I.EQ.NO) IINPUT=8 PAL07100
C          IF(I.EQ.N1) IINPUT=12 PAL07110
C          IF(I.EQ.N2) IINPUT=16 PAL07120
C          IF(I.EQ.N3) IINPUT=20 PAL07130
C          DO 24 J=1,7 PAL07140
24  IBUF(J,1)=IBUF(J+1,1) PAL07150

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ISUF(8,1)=I
IF(.NOT. ( (I.EQ.A).OR.(I.EQ.B).OR.(I.EQ.ISLASH).OR.(I.EQ.IOR)
1 .OR.(I.EQ.LAND).OR.(I.EQ.ICOLON) ) ) GO TO 21
DO 30 I=1,4
30 FIXBUF(I)=FIXBUF(I+1)
FIXBUF(5)=IPAGE(IC,IL)
GO TO 21
40 IMATCH=0
DO 60 J=1,14
LMATCH=.TRUE.
DO 50 I=1,5
50 LMATCH=LMATCH .AND. ( FIXBUF(I).EQ.TABLE(I,J) )
60 IF(LMATCH) IMATCH=J
IF(IMATCH.EQ.0) GO TO 100
IF(.NOT.LFIRST) GO TO 35
LFIRST=.FALSE.
DO 90 I=1,32
LFUSES(I,IPROD)=.TRUE.
90 IBLOW = IBLOW + 1
35 DO 90 I=1,4
IF( (IMATCH-7).LE.0 ) GO TO 50
ISUM=IINPUT*I
LFUSES(ISUM,IPROD)=.FALSE.
IBLOW = IBLOW - 1
IMATCH=IMATCH-8
90 IMATCH=IMATCH+IMATCH
LBUF(1)=.TRUE.
CALL PLOT(LBUF,IBUF,LFUSES,IPROD,TITLE,.FALSE.,ITYPE,
1 LPROD,IOP,IBLOW,IPCTR)
100 LFIX=.FALSE.
CALL INCR(IC,IL,LFIX)
RETURN
END
C
C*****
C
SUBROUTINE ECHO(IPAL,INOAI,IOT,INOO,REST,PATNUM,TITLE,COMP)
C THIS SUBROUTINE PRINTS THE PAL DESIGN SPECIFICATION INPUT FILE
C IMPLICIT INTEGER (A-Z)
INTEGER IPAL(4),REST(73),PATNUM(60),TITLE(80),COMP(80)
COMMON /PGE/ IPAGE(80,200)
COMMON /LUNIT/ PMS,PJF,PDF
COMMON /FTEST/ IFUNCT,IDESC,IEND
DATA IBLANK/' '/
WRITE(POF,5) IPAL,INOAI,IOT,INOO,REST,PATNUM,TITLE,COMP
5 FORMAT(/,' ',4A1,A1,A1,A1,73A1,/, ' ',80A1,/, ' ',80A1,/, ' ',80A1)
DO 20 IL=1,IEND
IC=31
10 IC=IC-1
IF( IPAGE(IC,IL).EQ.IBLANK.AND.IC.GT.1 ) GO TO 10
WRITE(POF,15) (IPAGE(I,IL),I=1,IC)
15 FORMAT(' ',80A1)
20 CONTINUE
RETURN
END

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```

C
C*****
C
SUBROUTINE CAT
THIS SUBROUTINE PRINTS THE PALASM CATALOG
IMPLICIT INTEGER (A-Z)
COMMON /LUNIT/ PMS,POF,PDF
WRITE(PMS,10)
10 FORMAT(/,' THIS PALASM AIDS THE USER IN THE DESIGN AND',
1 ' PROGRAMMING OF THE',/, ' SERIES 20 PAL FAMILY. THE',
2 ' FOLLOWING OPTIONS ARE PROVIDED:',
3 ' ECHO (E) - PRINTS THE PAL DESIGN',
4 ' SPECIFICATION',
5 ' PINOUT (O) - PRINTS THE PINOUT OF THE PAL',
6 ' SIMULATE (T) - EXERCISES THE FUNCTION TABLE',
7 ' VECTORS IN THE LOGIC',/, ' ',
8 ' EQUATIONS AND GENERATES TEST VECTORS',
9 ' PLOT (P) - PRINTS THE ENTIRE FUSE PLOT')
WRITE(PMS,20)
20 FORMAT(/,' BRIEF (B) - PRINTS ONLY THE USED PRODUCT LINES',
1 ' OF THE FUSE PLOT',/, ' PHANTOM',
2 ' FUSES ARE OMITTED',
3 ' HEX (H) - GENERATES HEX PROGRAMMING FORMAT',
4 ' SHORT (S) - GENERATES HEX PROGRAMMING FORMAT',
5 ' BHLF (L) - GENERATES BHLF PROGRAMMING FORMAT',
6 ' BNPF (N) - GENERATES BNPF PROGRAMMING FORMAT',
7 ' CATALOG (C) - PRINTS THE PALASM CATALOG',
8 ' QUIT (Q) - EXIT PALASM',
9 ' JEDEC (Y) - JEDEC FORMAT FOR DATA I/O PROGRAMMER',
A ' FAULT (F) - FAULT TESTING ')
RETURN
END
C
C*****
C
SUBROUTINE PINOUT(IPAL,INOAI,IOT,INOO,TITLE)
THIS SUBROUTINE PRINTS THE PINOUT OF THE PAL
IMPLICIT INTEGER (A-Z)
INTEGER IPAL(4),TITLE(80),PIN(12,20),IIN(7,2)
COMMON /PGE/ IPAGE(80,200)
COMMON /LUNIT/ PMS,POF,PDF
DATA IBLANK/' ',ISTAR/'*'/
DO 10 J=1,20
DO 5 I=1,12
5 PIN(I,J)=IBLANK
10 CONTINUE
15 DO 25 J=1,2
DO 20 I=1,7
20 IIN(I,J)=IBLANK
25 CONTINUE
IIN(2,1)=IPAL(1)
IIN(4,1)=IPAL(2)
IIN(6,1)=IPAL(3)
IIN(1,2)=IPAL(4)
IIN(3,2)=INOAI

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IIN(5,2)=IOT	PAL08260
IIN(7,2)=INOO	PAL08270
J=0	PAL08280
IL=0	PAL08290
30 IC=0	PAL08300
IL=IL+1	PAL08310
35 IC=IC+1	PAL08320
40 IF(IC.GT.80) GO TO 30	PAL08330
IF(IPAGE(IC,IL).EQ.IBLANK) GO TO 35	PAL08340
J=J+1	PAL08350
IF(J.GT.20) GO TO 60	PAL08360
DO 55 I=1,12	PAL08370
PIN(I,J)=IPAGE(IC,IL)	PAL08380
IC=IC+1	PAL08390
IF(IC.GT.80) GO TO 40	PAL08400
IF(IPAGE(IC,IL).EQ.IBLANK) GO TO 40	PAL08410
55 CONTINUE	PAL08420
60 DO 75 J=1,10	PAL08430
II=0	PAL08440
65 II=II+1	PAL08450
IF(II.EQ.13) GO TO 75	PAL08460
IF(PIN(II,J).NE.IBLANK) GO TO 65	PAL08470
I=13	PAL08480
70 I=I-1	PAL08490
II=II-1	PAL08500
PIN(I,J)=PIN(II,J)	PAL08510
PIN(II,J)=IBLANK	PAL08520
IF(II.NE.1) GO TO 70	PAL08530
75 CONTINUE	PAL08540
WRITE(POF,76) TITLE	PAL08550
76 FORMAT(/,' ',80A1)	PAL08560
WRITE(POF,76) ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,	PAL08570
1 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,	PAL08580
2 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,	PAL08590
3 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,	PAL08600
78 FORMAT(/,' ',18X,14A1,3X,14A1,	PAL08610
1 /,' ',18X,A1,13X,A1,1X,A1,13X,A1)	PAL08620
JJ=20	PAL08630
DO 83 J=1,10	PAL08640
WRITE(POF,80) ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR	PAL08650
30 FORMAT(' ',15X,4A1,29X,4A1)	PAL08660
WRITE(POF,81) (PIN(I,J),I=1,12),ISTAR,J,ISTAR,	PAL08670
1 (IIN(I,1),I=1,7),ISTAR,JJ,ISTAR,(PIN(I,JJ),I=1,12)	PAL08680
81 FORMAT(' ',12A1,3X,A1,12,A1,11X,7A1,11X,A1,12,A1,3X,12A1)	PAL08690
WRITE(POF,82) ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR	PAL08700
82 FORMAT(' ',15X,4A1,29X,4A1)	PAL08710
WRITE(POF,84) ISTAR,(IIN(I,2),I=1,7),ISTAR	PAL08720
84 FORMAT(' ',18X,A1,11X,7A1,11X,A1)	PAL08730
DO 86 II=1,2	PAL08740
DO 85 I=1,7	PAL08750
85 IIN(I,II)=IBLANK	PAL08760
86 CONTINUE	PAL08770
JJ=JJ-1	PAL08780
86 CONTINUE	PAL08790
WRITE(POF,90) ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,	PAL08800

```

1            ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,      PAL08810
2            ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,      PAL08820
3            ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR      PAL08830
90 FORMAT(' ',18X,31A1)      PAL08840
   RETURN      PAL08850
   END      PAL08860
C      PAL08870
C*****PAL08880
C      PAL08890
   SUBROUTINE PLOT(LBUF,IBUF,LFUSES,IPROD,TITLE,LDUMP,ITYPE,      PAL08900
   1            LPROD,IOP,IBLOW,IPCTRO)      PAL08910
C THIS THIS SUBROUTINE PRODUCES THE FUSE PLOT      PAL08920
   IMPLICIT INTEGER (A-Z)      PAL08930
   INTEGER IBUF(8,20),IOUT(64),ISAVE(64,32),TITLE(80)      PAL08940
   LOGICAL LBUF(20),LFUSES(32,64),LDUMP,LPROD(80)      PAL08950
   COMMON /LUNIT/ PMS,POF,PDF      PAL08960
   DATA ISAVE/2048*' ',IAND/'*',IOR/'+',ISLASH/'',/      PAL08970
   1        IDASH/'-',X/'X',IBLANK/' ',P/'P',B/'B',/      PAL08980
   2        HIFANT/'O'/      PAL08990
   IF(LDUMP) GO TO 60      PAL09000
   IF(ISAVE(IPROD,1).NE.IBLANK) RETURN      PAL09010
   IF(LBUF(1)) GO TO 5      PAL09020
   DO 30 J=1,31      PAL09030
   30        ISAVE(IPROD,J)=ISAVE(IPROD,J+1)      PAL09040
   ISAVE(IPROD,32)=ISLASH      PAL09050
   5        DO 20 I=1,8      PAL09060
          IF( ISAVE(IPROD,1).NE.IBLANK ) RETURN      PAL09070
          IF( IBUF(I,1).EQ.IBLANK ) GO TO 20      PAL09080
          DO 10 J=1,31      PAL09090
   10        ISAVE(IPROD,J)=ISAVE(IPROD,J+1)      PAL09100
          ISAVE(IPROD,32)=IBUF(I,1)      PAL09110
   20        CONTINUE      PAL09120
   IF(ISAVE(IPROD,1).NE.IBLANK) RETURN      PAL09130
   40 DO 50 J=1,31      PAL09140
   50        ISAVE(IPROD,J)=ISAVE(IPROD,J+1)      PAL09150
   ISAVE(IPROD,32)=IAND      PAL09160
   RETURN      PAL09170
C      PAL09180
   PRINT FUSE PLOT      PAL09180
   60 WRITE(POF,62) TITLE      PAL09190
   62 FORMAT(/,' ',80A1,/,      PAL09200
   1 '                            11 1111 1111 2222 2222 2233',/,      PAL09210
   2 '            0123 4567 8901 2345 6789 0123 4567 8901',/)      PAL09220
   DO 100 I88PRO=1,57,8      PAL09230
   DO 94 I8PRO=1,8      PAL09240
          IPROD=I88PRO+I8PRO-1      PAL09250
          ISAVE(IPROD,32)=IBLANK      PAL09260
          DO 70 I=1,32      PAL09270
          IF( ISAVE(IPROD,1).NE.IBLANK ) GO TO 70      PAL09280
          DO 65 J=1,31      PAL09290
          ISAVE(IPROD,J)=ISAVE(IPROD,J+1)      PAL09300
   65        CONTINUE      PAL09310
          ISAVE(IPROD,32)=IBLANK      PAL09320
   70        CONTINUE      PAL09330
          DO 80 I=1,32      PAL09340
          IOUT(I)=K      PAL09350

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```

      IF ( LFUSES(I,IPROD) ) IOUT(I)=IDASH
      IOUT(I+32)=ISAVE(IPROD,I)
80    CONTINUE
      IF (ITYPE.LE.4) CALL FANTOM(ITYPE,IOUT,IPROD,IBPRO)
      IPROD=IPROD-1
      DO 85 J=1,32
          IF ( IOP.EQ.B.AND.IOUT(J).EQ.HIFANT ) IOUT(J)=IBLANK
85    CONTINUE
      IF ( (IOP.EQ.P).OR.(IOP.EQ.B.AND.(LPROD(IPROD+1))) )
1     WRITE(POF,90) IPROD,IOUT
90    FORMAT(' ',I2,5(' ',4A1), ' ',32A1)
94    CONTINUE
      WRITE(POF,95)
96    FORMAT(1X)
100   CONTINUE
      WRITE(POF,110)
110  FORMAT(/,
1' LEGEND: X : FUSE NOT BLOWN (L,N,0) - : FUSE BLOWN (n,P,1)')
      IF ( IOP.EQ.P.AND.ITYPE.LE.4 ) WRITE(POF,111)
111  FORMAT(
1' J : PHANTOM FUSE (L,N,0) O : PHANTOM FUSE (H,P,1)')
      WRITE(POF,112) IBLOW
112  FORMAT(/, ' NUMBER OF FUSES BLOWN = ',I4)
      RETURN
      END
C
C*****
C
      SUBROUTINE HEX(LFUSES,IOP)
C     THIS SUBROUTINE GENERATES HEX PROGRAMMING FORMATS
      IMPLICIT INTEGER (A-Z)
      INTEGER ZTABLE(16), ITEMP(64), ZCSUM(4)
      LOGICAL LFUSES(32,64)
      INTEGER SOH,STX,ETX,BEL
      COMMON /LUNIT/ PMS,POF,PDF
      DATA H/'H'//,S/'S'//,IBLANK/' '//,
1     ZTABLE/'0','1','2','3','4','5','6','7',
2     '8','9','A','B','C','D','E','F'//
      DATA SOH /Z01000000/, STX /Z02000000/,
      ETX/Z03000000/, BEL /Z07000000/
      CSUM=0
      IF (IOP.EQ.h) WRITE(PDF,10)
10   FORMAT(//, ' .',//)
C***** NOTE: SOME PROM PROGRAMMERS NEED A START CHARACTER.
C***** THIS PROGRAM OUTPUTS AN STX FOR THE DATA I/O MODEL 9
C***** (USE SOH FOR MODEL 5)
      WRITE(PDF,5) BEL,BEL,BEL,BEL,BEL,BEL,BEL,BEL,STX,SOH
5   FORMAT(' ',9A1)
      DO 40 I=1,33,32
      INC=I-1
      DO 40 IPROD=1,7,2
      DO 20 J=1,2
      DO 20 IINPUT=1,32
      IHEX=0
      ISUM2=IPROD + J-1 + INC

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LFUSES(IINPUT,IPROD*5)=.FALSE. PAL10460
LFUSES(IINPUT,IPROD*6)=.FALSE. PAL10470
12 LFUSES(IINPUT,IPROD*7)=.FALSE. PAL10480
   IF(ITYPE.GE.3) GO TO 18 PAL10490
   DO 14 IPROD=17,41,8 PAL10500
     LFUSES(IINPUT,IPROD*2)=.FALSE. PAL10510
     LFUSES(IINPUT,IPROD*3)=.FALSE. PAL10520
14   IF(ITYPE.GE.2) GO TO 16 PAL10530
     DO 16 IPROD=1,57,8 PAL10540
     LFUSES(IINPUT,IPROD*2)=.FALSE. PAL10550
     LFUSES(IINPUT,IPROD*3)=.FALSE. PAL10560
16 CONTINUE PAL10570
20 IF( (ITYPE.EQ.1) .OR. ((ITYPE.EQ.4) .AND. (IOT.EQ.L) ) ) RETURN PAL10580
   DO 99 IINPUT=1,32 PAL10590
     DO 30 IPROD=1,8 PAL10600
       LFUSES(IINPUT,IPROD*0) = (IOT.NE.L) PAL10610
       IF(IOT.NE.C) LFUSES(IINPUT,IPROD*56) = (IOT.NE.L) PAL10620
30     IF(ITYPE.LE.2) GO TO 99 PAL10630
       DO 40 IPROD=1,8 PAL10640
         LFUSES(IINPUT,IPROD*8) = (IOT.NE.L) PAL10650
         IF(IOT.NE.C) LFUSES(IINPUT,IPROD*48) = (IOT.NE.L) PAL10660
40     IF(ITYPE.LE.3) GO TO 99 PAL10670
       DO 50 IPROD=1,8 PAL10680
         LFUSES(IINPUT,IPROD*16) = (IOT.NE.L) PAL10690
50     IF(IOT.NE.C) LFUSES(IINPUT,IPROD*40) = (IOT.NE.L) PAL10700
99 CONTINUE PAL10710
RETURN PAL10720
END PAL10730
C ***** PAL10740
C ***** PAL10750
C ***** PAL10760
SUBROUTINE BINR(LFUSES,H,L) PAL10770
C THIS SUBROUTINE GENERATES BINARY PROGRAMMING FORMATS PAL10780
IMPLICIT INTEGER (A-Z) PAL10790
INTEGER ITEMP(4,8) PAL10800
LOGICAL LFUSES(32,64) PAL10810
COMMON /LJNII/ PMS,PDF,PDF PAL10820
WRITE(PDF,10) PAL10830
10 FORMAT(//, ' .',//) PAL10840
DO 20 I=1,33,32 PAL10850
INC=I-1 PAL10860
DO 20 IPROD=1,8 PAL10870
DO 20 J=1,25,8 PAL10880
DO 15 K=1,8 PAL10890
IINPUT=J+K-1 PAL10900
ITEMP(1,K)=L PAL10910
ITEMP(2,K)=L PAL10920
ITEMP(3,K)=L PAL10930
ITEMP(4,K)=L PAL10940
ISUM3=IPROD+INC PAL10950
IF(LFUSES(IINPUT,ISUM3+0)) ITEMP(4,K)=H PAL10960
IF(LFUSES(IINPUT,ISUM3+8)) ITEMP(3,K)=H PAL10970
IF(LFUSES(IINPUT,ISUM3+16)) ITEMP(2,K)=H PAL10980
IF(LFUSES(IINPUT,ISUM3+24)) ITEMP(1,K)=H PAL10990
15 CONTINUE PAL11000

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RETURN                                     PAL11560
END                                         PAL11570
C                                           PAL11580
C*****                                     PAL11590
C                                           PAL11600
      SUBROUTINE IODC2                       PAL11610
C***** THIS ROUTINE IS OPTIONAL, IT MAY BE USED TO TURN PERIPHERALS ON PAL11620
      IMPLICIT INTEGER (A-Z)                PAL11630
      INTEGER BEL,DC2,ESC,FF,NUL            PAL11640
      COMMON /LUNIT/ PMS,POF,PDF           PAL11650
      DATA BEL /Z07000000/, DC2 /Z22000000/ PAL11660
      WRITE (PDF,10) DC2,BEL                PAL11670
10  FORMAT(' ',2A1)                         PAL11680
      RETURN                                 PAL11690
      END                                     PAL11700
C                                           PAL11710
C*****                                     PAL11720
C                                           PAL11730
      SUBROUTINE IODC4                       PAL11740
C***** THIS ROUTINE IS OPTIONAL, IT MAY BE USED TO TURN PERIPHERALS OFF PAL11750
      IMPLICIT INTEGER (A-Z)                PAL11760
      INTEGER BEL,DC3,DC4                  PAL11770
      COMMON /LUNIT/ PMS,POF,PDF           PAL11780
      DATA BEL /Z07000000/, DC3/Z23000000/, DC4/Z24000000/ PAL11790
      WRITE (PDF,10) BEL,DC3,DC4           PAL11800
10  FORMAT(' ',3A1)                         PAL11810
      RETURN                                 PAL11820
      END                                     PAL11830
C                                           PAL11840
C*****                                     PAL11850
C                                           PAL11860
      SUBROUTINE TEST(LPHASE,LBUF,TITLE,IC,IL,ILE,ISYM,IBUF,ITYPE,
1      INOO,LPFIX,IPCTR,LERR,ISAF,IPCTR1,LSA11,LSA01) PAL11870
C THIS SUBROUTINE PERFORMS THE FUNCTION TABLE SIMULATION. PAL11880
C AND GENERATES TEST VECTORS.              PAL11890
      IMPLICIT INTEGER (A-Z)                PAL11900
      INTEGER ISYM(8,20),ISYM1(8,20),IBUF(8,20),IVECT(20),IVECTP(20), PAL11920
1      ISTATE(20),ISTAT1(20),IPIN(20),TITLE(80),IPCTR PAL11930
      LOGICAL LBLANK,LLEFT,LAND,LOB,LSLASH,LEQUAL,LRIGHT,LXOR,LXNOR, PAL11940
1      LFIX,LSAME,XORFND,LERR,LPHASE(20),LPHAS1(20),LBUF(20), PAL11950
2      LOUT(20),LOUTP(20),LCLOCK,LPTRST,LCTRST,LENABL(20),NREG, PAL11960
3      LSA11,LSA12,LSA01                    PAL11970
      INTEGER BEL                           PAL11980
      COMMON LBLANK,LLEFT,LAND,LOB,LSLASH,LEQUAL,LRIGHT,LXOR,LXNOR PAL11990
      COMMON /PGE/ IPAGE(80,200)            PAL12000
      COMMON /LUNIT/ PMS,POF,PDF           PAL12010
      COMMON /FTEST/ IFUNCT,IDESC,IEND      PAL12020
      DATA IDASH/'-'/,L/'L'/,H/'H'/,X/'X'/,C/'C'/,Z/'Z'/,NO/'O'/, PAL12030
1      N1/'1'/,ERR/'?'/,IBLANK/' '/,COMENT/' ':'/,I4/'4'/,I6/'6'/, PAL12040
2      I8/'8'/                               PAL12050
      DATA BEL/Z07000000/                  PAL12060
C PRINT AN ERROR MESSAGE IF NO FUNCTION TABLE IS SUPPLIED PAL12070
      IF(IFUNCT.NE.0) GO TO 3                PAL12080
      WRITE (PMS,2)                          PAL12090
2  FORMAT(/,' FUNCTION TABLE MUST BE SUPPLIED IN ORDER TO PERFORM', PAL12100

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1      ' SIMULATION')                                PAL12110
      RETURN                                          PAL12120
C      PRINT TITLE                                  PAL12130
3     IF ((.NOT,LSA11).AND,(.NOT,LSA01)) WRITE(POF,4) TITLE PAL12140
4     FORMAT(/,' ',80A1,/)                          PAL12150
C      INITIALIZE LERR (FUNCTION TABLE ERROR FLAG) TO NO ERROR PAL12160
      LERR=.FALSE.                                  PAL12170
C      INITIALIZE NERR (NUMBER OF FUNCTION TABLE ERRORS) TO NO ERRORS PAL12180
      NERR=0                                         PAL12190
C      INITIALIZE ITRST (THREE-STATE ENABLE FUNCTION TABLE PIN NUMBER) PAL12200
      ITRST=0                                        PAL12210
C      SET THE STARTING POINT OF THE FUNCTION TABLE TO COLUMN 0 PAL12220
C      AND IFUNCT + 1                                PAL12230
      IC=0                                           PAL12240
      IL=IFUNCT + 1                                  PAL12250
C      INITIALIZE SA1/SA0 PARAMETERS                PAL12260
      IPCTR3=0                                       PAL12270
      IEQN=0                                         PAL12280
      IPCTR=0                                        PAL12290
C
C      MAKE A DUMMY CALL TO INCR                     PAL12300
C      CALL INCR(IC,IL,LFIX)                         PAL12310
C      GET THE FUNCTION TABLE PIN LIST (UP TO 18)  PAL12320
C      GO ONE MORE THAN MAX TO LOOK FOR DASHED LINE PAL12330
      DO 10 I=1,19                                   PAL12340
      CALL GETSYM(LPHAS1,ISYM1,I,IC,IL,LFIX)        PAL12350
      DO 5 J=1,8                                     PAL12360
5     IBUF(J,1)=ISYM1(J,1)                          PAL12370
      IF(IBUF(8,1).EQ.IDASH) GO TO 12               PAL12380
      CALL MATCH(IMATCH,IBUF,ISYM)                 PAL12390
      IF(IMATCH.NE.0) GO TO 7                       PAL12400
      WRITE(PMS,6) (IBUF(J,1),J=1,8)               PAL12410
6     FORMAT(/,' FUNCTION TABLE PIN LIST ERROR AT', 8A1) PAL12420
      RETURN                                         PAL12430
7     LOUT(I)=.FALSE.                               PAL12440
      ISTAT(I)=X                                    PAL12450
      IVECTP(I)=X                                   PAL12460
C      IF APPROPRIATE PAL TYPE, REMEMBER LOCATION OF CLOCK AND THREE-STATE PAL12470
C      ENABLE PIN IN FUNCTION TABLE PIN LIST      PAL12480
      IF(ITYPE.NE.6) GO TO 10                       PAL12490
      IF(IMATCH.EQ.1) ICLOCK=I                     PAL12500
      IF(IMATCH.EQ.11) ITRST=I                     PAL12510
10    IPIN(I)=IMATCH                                PAL12520
C      ALL SIGNAL NAMES FOR THE FUNCTIONAL TEST HAVE BEEN READ IN PAL12530
C      ADJUST COUNT                                 PAL12540
12    IMAX=I-1                                       PAL12550
      NVECT=0                                        PAL12560
C
C*****START OF MAIN LOOP FOR SIMULATION*****    PAL12570
C
C      INITIALLY THERE ARE NO FAULTS. IPCTR2 IS THE POINTER FOR PAL12580
C      TOTAL NUMBER OF PRODUCT TERMS. IEQN IS EQUATION COUNT. PAL12590
C      IPCTR3 IS THE PRODUCT TERM POINTER IN A PARTICULAR EQN. PAL12600
10    IPCTR2=0                                       PAL12610

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	IEQN=0	PAL12660
	IPCTR3=0	PAL12670
	LSA12=.FALSE.	PAL12680
	LSA02=.FALSE.	PAL12690
C	NVECT=NVECT+1	PAL12700
	IC1=J	PAL12710
	IL1=ILE	PAL12720
C	GO PASSED COMMENT LINES	PAL12730
23	IF(IPAGE(I,IL).NE.COMENT) GO TO 24	PAL12740
	IL=IL+1	PAL12750
	GO TO 23	PAL12760
24	CONTINUE	PAL12770
C	GETS VECTORS FROM FUNCTION TABLE	PAL12780
	DO 20 I=1,INAX	PAL12790
	IF(IPAGE(IC,IL).EQ.IBLANK) GO TO 21	PAL12800
	GO TO 22	PAL12810
21	IC=IC+1	PAL12820
	IF(IPAGE(IC,IL).EQ.IBLANK) GO TO 21	PAL12830
22	IVECT(I)=IPAGE(IC,IL)	PAL12840
	IC=IC+1	PAL12850
20	CONTINUE	PAL12860
C	ADVANCE LINE COUNT TO SKIP FUNCTION TABLE COMMENTS	PAL12870
	IL=IL+1	PAL12880
	IC=1	PAL12890
	IF(IVECT(I).EQ.IDASH) GO TO 95	PAL12900
C	CHECK FOR VALID FUNCTION TABLE VALUES (L,H,X,Z,C)	PAL12910
	DO 11 I=1,INAX	PAL12920
	IF(IVECT(I).EQ.L.OR.IVECT(I).EQ.H.OR.IVECT(I).EQ.X.OR.	PAL12930
1	IVECT(I).EQ.Z.OR.IVECT(I).EQ.C) GO TO 11	PAL12940
	WRITE(PMS,8) IVECT(I),NVECT	PAL12950
8	FORMAT(/, ' ',A1, ' IS NOT AN ALLOWED FUNCTION TABLE ENTRY',	PAL12960
1	IN VECTOR ',I3)	PAL12970
	RETURN	PAL12980
11	CONTINUE	PAL12990
C	INITIALIZE CLOCK AND THREE-STATE ENABLE FLAGS	PAL13000
	LCLOCK=.FALSE.	PAL13010
	LCTRST=.TRUE.	PAL13020
	LPTRST=.TRUE.	PAL13030
	DO 13 I=1,INAX	PAL13040
13	LENABL(I)=.TRUE.	PAL13050
C	INITIALIZE NREG (NOT REGISTERED OUTPUT) TO FALSE	PAL13060
	NREG=.FALSE.	PAL13070
C	INITIALIZE ISTATE ARRAY TO ALL X'S	PAL13080
	DO 15 I=1,20	PAL13090
15	ISTATE(I)=X	PAL13100
C	CHECK IF THIS PAL TYPE HAS REGISTERS	PAL13110
	IF(ITYPE.NE.6) GO TO 25	PAL13120
C	CHECK CLOCK AND THREE-STATE ENABLE PINS AND CHANGE FLAG IF NEEDED	PAL13130
	IF(IVECT(ICLOCK).EQ.C) LCLOCK=.TRUE.	PAL13140
	IF(ITRST.EQ.0) GO TO 25	PAL13150
	LSAME=((LPHASE(11)).AND.(LPHAS1(ITRST)).OR.	PAL13160
1	(.NOT.LPHASE(11)).AND.(.NOT.LPHAS1(ITRST)))	PAL13170
	IF(IVECT(ITRST).EQ.L.AND.(.NOT.LSAME).OR.	PAL13180
1	IVECT(ITRST).EQ.H.AND.(LSAME)) LPTRST=.FALSE.	PAL13190
		PAL13200

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IF(LPIRST) GO TO 25
C  DISABLE REGISTERED OUTPUTS IF APPROPRIATE
DO 46 I=1,IMAX
    J=IPIN(I)
    IF(J.EQ.14.OR.J.EQ.15.OR.J.EQ.16.OR.J.EQ.17) LENABL(I)=.FALSE.
    IF( INOO.EQ.16.AND.(J.EQ.13.OR.J.EQ.18) ) LENABL(I)=.FALSE.
    IF( INOO.EQ.18.AND.(J.EQ.12.OR.J.EQ.13
1      .OR.J.EQ.18.OR.J.EQ.19) ) LENABL(I)=.FALSE.
46 CONTINUE
C
C*****SCAN THROUGH THE LOGIC EQUATIONS*****
C
C  MAKE A DUMMY CALL TO INCR
25 CALL INCR(IC1,IL1,LFIX)
26 CALL GETSYM(LBUF,IBUF,1,IC1,IL1,LFIX)
IF(LLEFT) GO TO 29
27 IF(.NOT.LEQUAL) GO TO 26
C
IF(LEQUAL) IEQN=IEQN+1
C
C  EVALUATE CONDITIONAL THREE-STATE PRODUCT LINE
29 IF(LEQUAL) GO TO 35
NREG=.TRUE.
33 CALL GETSYM(LBUF,IBUF,1,IC1,IL1,LFIX)
CALL MATCH(IINP,IBUF,ISYM1)
C  CHECK FOR GND, VCC, /GND, OR /VCC IN CONDITIONAL THREE-STATE
C  PRODUCT LINE
IF(IINP.NE.0) GO TO 32
CALL MATCH(IMATCH,IBUF,ISYM)
ILL=IL1
IF( IINP.EQ.0.AND.IMATCH.NE.10.AND.IMATCH.NE.20 ) GO TO 100
IF( IMATCH.EQ.10.AND.(LBUF(1)).OR.
1  IAATCH.EQ.20.AND.(.NOT.LBUF(1)) ) LCTRST=.FALSE.
GO TO 34
32 ITEST=IVECT(IINP)
IF( ITEST.EQ.L.AND.( LPHAS1(IINP)).AND.( LBUF(1))
1.OR. ITEST.EQ.H.AND.( LPHAS1(IINP)).AND.(.NOT.LBUF(1))
2.OR. ITEST.EQ.H.AND.(.NOT.LPHAS1(IINP)).AND.( LBUF(1))
3.OR. ITEST.EQ.L.AND.(.NOT.LPHAS1(IINP)).AND.(.NOT.LBUF(1))
4 ) LCTRST=.FALSE.
IF(ITEST.EQ.X.OR.ITEST.EQ.Z) LCTRST=.FALSE.
34 IF(LAND) GO TO 33
GO TO 27
C
C  EVALUATE THE LOGIC EQUATION
C
C  FIND THE PIN NUMBER OF THE OUTPUT VECTORS
C
35 IPCTR3=0
C
CALL MATCH(IOUTP,IBUF,ISYM1)
C  FLAG UNREGISTERED OUTPUTS
CALL MATCH(IOUT,IBUF,ISYM)
IF(ITYPE.LE.5) NREG=.TRUE.
IF( (INOO.EQ.14.OR.INOO.EQ.16).AND.(IOUT.EQ.12.OR.IOUT.EQ.19) )

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PAL13210
PAL13220
PAL13230
PAL13240
PAL13250
PAL13260
PAL13270
PAL13280
PAL13290
PAL13300
PAL13310
PAL13320
PAL13330
PAL13340
PAL13350
PAL13360
PAL13370
PAL13380
PAL13390
PAL13400
PAL13410
PAL13420
PAL13430
PAL13440
PAL13450
PAL13460
PAL13470
PAL13480
PAL13490
PAL13500
PAL13510
PAL13520
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PAL13560
PAL13570
PAL13580
PAL13590
PAL13600
PAL13610
PAL13620
PAL13630
PAL13640
PAL13650
PAL13660
PAL13670
PAL13680
PAL13690
PAL13700
PAL13710
PAL13720
PAL13730
PAL13740
PAL13750

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1	NREG=.TRUE.	PAL13760
	IF((IN00.EQ.I4).AND.(IOUT.EQ.I3.OR.IOUI.EQ.I8)) NREG=.TRUE.	PAL13770
	ILL=ILL	PAL13780
	IF(IOUTP.EQ.0) GO TO 100	PAL13790
	IF(NREG) LENABL(IOUTP)=LCTRST	PAL13800
	LOUT(IOUTP)=.TRUE.	PAL13810
	IF(.NOT.LCTRST) LOUT(IOUTP)=.FALSE.	PAL13820
	LCTRST=.TRUE.	PAL13830
	LOUTP(IOUTP)=LBUF(1)	PAL13840
C	DETERMINE PRODUCT TERM AND EVENTUALLY SUM FOR OUTPUT KEEPING	PAL13850
C	TRACK TO SEE IF AN XOR (EXCLUSIVE OR) HAS BEEN FOUND	PAL13860
	XORSUM=H	PAL13870
	XORFND=.FALSE.	PAL13880
	ISUM=L	PAL13890
C		PAL13900
28	IPCTR2=IPCTR2+1	PAL13910
	IPCTR3=IPCTR3+1	PAL13920
C		PAL13930
	IPCTR=IPCTR+1	PAL13940
	IPROD=H	PAL13950
30	ILL=ILL	PAL13960
	CALL GETSYM(LBUF,IBUF,1,IC1,IL1,LFIX)	PAL13970
	IF(.NOT.LFIX) GO TO 39	PAL13980
C	EVALUATE THE FIXED SYMBOLS FOUND IN THE PAL16X4 AND PAL16A4	PAL13990
	LFIX=.FALSE.	PAL14000
	CALL FIXTST(LPHAS1,LBUF,IC1,IL1,ISYM,ISYM1,IBUF,	PAL14010
1	IVECT,IVECTP,ITEST,LCLOCK,NREG,LFIX)	PAL14020
	IF(LPMOD.EQ.H) IPROD=ITEST	PAL14030
	GO TO 36	PAL14040
39	CALL MATCH(IINP,IBUF,ISYM1)	PAL14050
	IF(IINP.NE.0) GO TO 47	PAL14060
	CALL MATCH(IMATCH,IBUF,ISYM)	PAL14070
	IF(IMATCH.NE.10.AND.IMATCH.NE.20) GO TO 100	PAL14080
C	TWEAK FOR GND AND VCC IN PRODUCT LINE	PAL14090
	IF(IMATCH.EQ.10) ITEST=L	PAL14100
	IF(IMATCH.EQ.20) ITEST=H	PAL14110
	IINP=19	PAL14120
	LPHAS1(19)=.TRUE.	PAL14130
	GO TO 37	PAL14140
47	ITEST=IVECT(IINP)	PAL14150
C	GET REGISTERED FEED BACK VALUES	PAL14160
	IF(NREG) GO TO 37	PAL14170
	CALL MATCH(IIFB,IBUF,ISYM)	PAL14180
	IF((IN00.EQ.I4.OR.IN00.EQ.I6.OR.IN00.EQ.I8).AND.	PAL14190
1	(IIFB.EQ.14.OR.IIFB.EQ.15.OR.IIFB.EQ.16.OR.IIFB.EQ.17))	PAL14200
2	ITEST=IVECTP(IINP)	PAL14210
	IF((IN00.EQ.I6.OR.IN00.EQ.I8).AND.(IIFB.EQ.13.OR.IIFB.EQ.18))	PAL14220
1	ITEST=IVECTP(IINP)	PAL14230
	IF(IN00.EQ.I8.AND.(IIFB.EQ.12.OR.IIFB.EQ.19))	PAL14240
1	ITEST=IVECTP(IINP)	PAL14250
37	IF(ITEST.EQ.X.OR.ITEST.EQ.Z) ITEST=L	PAL14260
	IF(ITEST.EQ.L.AND.(LPHAS1(IINP)).AND.(LBUF(1)	PAL14270
	1.OR.ITEST.EQ.H.AND.(LPHAS1(IINP)).AND.(.NOT.LBUF(1)	PAL14280
	2.OR.ITEST.EQ.H.AND.(.NOT.LPHAS1(IINP)).AND.(LBUF(1)	PAL14290
	3.OR.ITEST.EQ.L.AND.(.NOT.LPHAS1(IINP)).AND.(.NOT.LBUF(1)	PAL14300

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4 ) IPROD=L PAL14310
C CHECK FOR A PARTICULAR PRODUCT TERM AND GO FOR SA1 TEST PAL14320
C IF((IPCTR2.EQ.IPCTR1).AND.(LSA11))GO TO 110 PAL14330
C PAL14340
C 38 IF(LRIGHT) CALL INCR(IC1,IL1,LFIX) PAL14350
C IF(LAND) GO TO 30 PAL14360
C PAL14370
C CHECK FOR A PARTICULAR PRODUCT TERM AND GO FOR SA0 TEST PAL14380
C IF((IPCTR2.EQ.IPCTR1).AND.(LSA01))GO TO 120 PAL14390
C PAL14400
C 121 IF(ISUM.EQ.L.AND.IPROD.EQ.X) ISUM=X PAL14410
C IF( (ISUM.NE.H).AND.IPROD.EQ.H ) ISUM=H PAL14420
C CHECK FOR XOR (EXCLUSIVE OR) AND SAVE INTERMEDIATE VALUE PAL14430
C IF(.NOT.LAOR) GO TO 31 PAL14440
C XORSUM=ISUM PAL14450
C XORFND=.TRUE. PAL14460
C ISUM=L PAL14470
C GO TO 28 PAL14480
C 31 IF(LOR) GO TO 28 PAL14490
C IPCTR3=0 PAL14500
C IF END OF EQUATION HAS BEEN FOUND, DETERMINE FINAL SUM AND SAVE ITPAL14520
C IF(.NOT.XORFND) ISTAT(IOUTP)=ISUM PAL14530
C IF( (XORFND).AND.((ISUM.EQ.L.AND.XORSUM.EQ.L).OR. PAL14540
C (ISUM.EQ.H.AND.XORSUM.EQ.H)) ) ISTAT(IOUTP)=L PAL14550
C IF( (XORFND).AND.((ISUM.EQ.H.AND.XORSUM.EQ.L).OR. PAL14560
C (ISUM.EQ.L.AND.XORSUM.EQ.H)) ) ISTAT(IOUTP)=H PAL14570
C IF( (XORFND).AND. (ISUM.EQ.X.OR. XORSUM.EQ.X) ) ISTAT(IOUTP)=X PAL14580
C REGISTER DOES NOT CHANGE STATE IF NO CLOCK PULSE IS RECEIVED PAL14590
C IF( (LCLOCK).OR.(NREG) ) GO TO 36 PAL14600
C LSAME = ( ( LOUTP(IOUTP)).AND.( LPHAS1(IOUTP)).OR. PAL14610
C (.NOT.LOUTP(IOUTP)).AND.(.NOT.LPHAS1(IOUTP)) ) PAL14620
C IF( IVECTP(IOUTP).EQ.L.AND.( LSAME) ) ISTAT(IOUTP)=L PAL14630
C IF( IVECTP(IOUTP).EQ.H.AND.( LSAME) ) ISTAT(IOUTP)=H PAL14640
C IF( IVECTP(IOUTP).EQ.L.AND.(.NOT.LSAME) ) ISTAT(IOUTP)=H PAL14650
C IF( IVECTP(IOUTP).EQ.H.AND.(.NOT.LSAME) ) ISTAT(IOUTP)=L PAL14660
C 36 NREG=.FALSE. PAL14670
C CHECK IF ALL EQUATIONS HAVE BEEN PROCESSED BY COMPARING CURRENT PAL14680
C LINE NUMBER WITH FUNCTION TABLE LINE NUMBER PAL14690
C IF(IDESC.NE.0.AND.IL1.LT.IFUNCT.AND.IL1.LT.IDESC.OR. PAL14700
C IDESC.EQ.0.AND.IL1.LT.IFUNCT) GO TO 27 PAL14710
C DETERMINE OUTPUT LOGIC VALUES PAL14720
C COMPARE OUTPUTS TO SEE IF VECTOR AGREES WITH RESULTS PAL14730
C DO 50 I=1,IMAX PAL14740
C IF( .NOT.LOUT(I) ) GO TO 50 PAL14750
C IF( ISTAT(I).EQ.X.AND.IVECT(I).EQ.X ) GO TO 50 PAL14760
C LSAME = ( ( LOUTP(I)).AND.( LPHAS1(I)).OR. PAL14770
C (.NOT.LOUTP(I)).AND.(.NOT.LPHAS1(I)) ) PAL14780
C IMESS=40 PAL14790
C IF(ISTATT(I).EQ.L.AND.IVECT(I).EQ.L.AND.(.NOT.LSAME)) IMESS=41 PAL14800
C IF(ISTATT(I).EQ.H.AND.IVECT(I).EQ.H.AND.(.NOT.LSAME)) IMESS=42 PAL14810
C IF(ISTATT(I).EQ.L.AND.IVECT(I).EQ.H.AND.( LSAME)) IMESS=42 PAL14820
C IF(ISTATT(I).EQ.H.AND.IVECT(I).EQ.L.AND.( LSAME)) IMESS=41 PAL14830
C IF( ( LENABL(I)).AND.IVECT(I).EQ.Z ) IMESS=43 PAL14840
C IF( (.NOT.LENABL(I)).AND.(LOUT(I)).AND.IVECT(I).NE.Z) IMESS=44 PAL14850

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C      IF (IMESS.NE.40) LERR=.TRUE.
C      IF NO FAULT GO FOR NEXT VECTOR ELSE GET OUT OF SIMULATION AND
C      START SIMULATION FOR THE NEXT PRODUCT TERM.
C      IF ((.NOT.LERR).AND.((LSA11).OR.(LSA01))) GO TO 50.
C      IF ((LERR).AND.((LSA11).OR.(LSA01))) GO TO 115
C
C      IF (IMESS.EQ.41) WRITE (PMS,41) NVECT, (ISYM1(J,I),J=1,8)
41  FORMAT(/,' FUNCTION TABLE ERROR IN VECTOR',I3,' PIN =',3A1,
1     ' EXPECT = H ACTUAL = L')
C      IF (IMESS.EQ.42) WRITE (PMS,42) NVECT, (ISYM1(J,I),J=1,8)
42  FORMAT(/,' FUNCTION TABLE ERROR IN VECTOR',I3,' PIN =',3A1,
1     ' EXPECT = L ACTUAL = H')
C      IF (IMESS.EQ.43) WRITE (PMS,43) NVECT, (ISYM1(J,I),J=1,8)
43  FORMAT(/,' FUNCTION TABLE ERROR IN VECTOR',I3,' PIN =',3A1,
1     /,' EXPECT = OUTPUT ENABLE ACTUAL = Z')
C      IF (IMESS.EQ.44) WRITE (PMS,44) NVECT, (ISYM1(J,I),J=1,8), IVECT(I)
44  FORMAT(/,' FUNCTION TABLE ERROR IN VECTOR',I3,' PIN =',3A1,
1     ' EXPECT = Z ACTUAL = ',A1)
C      IF ( (IMESS.NE.40).AND.(PMS.EQ.6) ) WRITE (PMS,45) BEL
45  FORMAT(' ',A1)
C      IF (IMESS.NE.40) IVECT(I)=ERR
C      IF (IMESS.NE.40) NERR=NERR+1
50  CONTINUE
C  CHANGE THE ORDER OF VECTORS FROM THE ORDER OF APPEARANCE IN THE
C  FUNCTION TABLE TO THAT OF THE PIN LIST AND TWEAK FOR OUTPUT
DO 65 I=1,20
  DO 55 J=1,IMAX
    IF (IPIN(J).NE.1) GO TO 55
    IF ( IVECT(J).EQ.L.OR.IVECT(J).EQ.H ) GO TO 51
    ISTATE(I)=IVECT(J)
    GO TO 65
51  LSAME=( ( LPHASE(I)).AND.( LPHAS1(J)).OR.
1     (.NOT.LPHASE(I)).AND.(.NOT.LPHAS1(J)) )
    IF ( INOO.EQ.N1.AND.(I.EQ.15.OR.I.EQ.16) ) LOUT(J)=.TRUE.
    IF ( (.NOT.LOUT(J)).AND.( LSAME).AND.
1     IVECT(J).EQ.L ) ISTATE(I)=NO
    IF ( (.NOT.LOUT(J)).AND.( LSAME).AND.
1     IVECT(J).EQ.H ) ISTATE(I)=N1
    IF ( (.NOT.LOUT(J)).AND.(.NOT.LSAME).AND.
1     IVECT(J).EQ.L ) ISTATE(I)=N1
    IF ( (.NOT.LOUT(J)).AND.(.NOT.LSAME).AND.
1     IVECT(J).EQ.H ) ISTATE(I)=NO
    IF ( ( LOUT(J)).AND.( LSAME).AND.
1     IVECT(J).EQ.L.AND.( LENABL(J) ) ISTATE(I)=L
    IF ( ( LOUT(J)).AND.( LSAME).AND.
1     IVECT(J).EQ.H.AND.( LENABL(J) ) ISTATE(I)=H
    IF ( ( LOUT(J)).AND.(.NOT.LSAME).AND.
1     IVECT(J).EQ.L.AND.( LENABL(J) ) ISTATE(I)=H
    IF ( ( LOUT(J)).AND.(.NOT.LSAME).AND.
1     IVECT(J).EQ.H.AND.( LENABL(J) ) ISTATE(I)=L
    IF ( IVECT(J).EQ.ERR ) ISTATE(I)=ERR
    GO TO 65
55  CONTINUE
C  SAVE PRESENT VECTORS FOR FEED BACK USED WITH NEXT SET OF VECTORS

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C	IF CLOCK PULSE AND NOT 2 (HI-Z IS ASYNCHRONOUS)	PAL15410
65	IF((LCLOCK).AND.IVECT(J).NE.2) IVECTP(J)=IVECT(J)	PAL15420
C	ASSIGN X TO GROUND PIN AND 1 TO VCC PIN	PAL15430
	ISTATE(10)=X	PAL15440
	ISTATE(20)=N1	PAL15450
C	PRINT TEST VECTORS	PAL15460
	IF((.NOT.LSA11).AND.(.NOT.LSA01))WRITE(POF,60)	PAL15470
	1 NVECT,(ISTATE(I),I=1,20)	PAL15480
60	FORMAT(' ',I3,' ',20A1)	PAL15490
	GO TO 90	PAL15500
C	TERMINATE SIMULATION	PAL15510
C		PAL15520
95	IF((.NOT.LERR).AND.(LSA11))WRITE(POF,150) IPCTR4,IEQN1	PAL15530
150	FORMAT(' ', ' PRODUCT: ',I3,' OF ',' EQUATION.',I3,'	PAL15540
	1 UNTESTED(SA1) FAULT')	PAL15550
	IF((.NOT.LERR).AND.(LSA01))WRITE(POF,155) IPCTR4,IEQN1	PAL15560
155	FORMAT(' ', ' PRODUCT: ',I3,' OF ',' EQUATION.',I3,'	PAL15570
	1 UNTESTED(SA0) FAULT')	PAL15580
C		PAL15590
	IF((.NOT.LERR).AND.((.NOT.LSA11).AND.(.NOT.LSA01)))WRITE(POF,67)	PAL15600
67	FORMAT(/,' PASS SIMULATION')	PAL15610
	IPCTR=IPCTR/(NVECT-1)	PAL15620
	IF((LERR).AND.((.NOT.LSA11).AND.(.NOT.LSA01)))	PAL15630
	1WRITE(POF,68) NERR	PAL15640
68	FORMAT(/,' NUMBER OF FUNCTION TABLE ERRORS = ',I3)	PAL15650
	RETURN	PAL15660
C	PRINT AN ERROR MESSAGE FOR AN UNDEFINED PIN NAME	PAL15670
100	ILERR=ILL+4	PAL15680
	WRITE(PMS,101) (IBUF(1,1),I=1,8),ILERR,(IPAGE(I,ILL),I=1,80)	PAL15690
101	FORMAT(/,' ERROR SYMBOL = ',BA1,' IN LINE NUMBER ',I3,	PAL15700
1	1 /,' ',B0A1,/,' THIS PIN NAME IS NOT DEFINED IN THE',	PAL15710
2	2 ' FUNCTION TABLE PIN LIST')	PAL15720
	RETURN	PAL15730
C		PAL15740
C	THE PRODUCT TERM IS PULLED HIGH AND THE PRODUCT NUMBER	PAL15750
C	AND EQN NUMBER IS REMEMBERED	PAL15760
110	IPROD=H	PAL15770
	LSA12=.TRUE.	PAL15780
	IEQN1=IEQN	PAL15790
	IPCTR4=IPCTR3	PAL15800
	GO TO 38	PAL15810
C		PAL15820
C		PAL15830
C		PAL15840
C	THE PRODUCT TERM IS TESTED FOR SA0 FAULT AND ALSO REMEMBERED	PAL15850
120	IPROD=L	PAL15860
	LSA02=.TRUE.	PAL15870
	IEQN1=IEQN	PAL15880
	IPCTR4=IPCTR3	PAL15890
	GO TO 121	PAL15900
C		PAL15910
C		PAL15920
C		PAL15930
C	IF NO FAULT THEN NEXT PRODUCT TERM	PAL15940
115	ISAF=ISAF+1	PAL15950

```

LERR=.FALSE.
RETURN
C
END
C*****
C
SUBROUTINE FIXIST(LPHAS1,LBUF,IC1,IL1,ISYM,ISYM1,IBUF,
1 IVECT,IVECTP,ITEST,LCLOCK,NREG,LFIX)
C THIS SUBROUTINE EVALUATES THE FIXED SYMBOLS FOUND IN THE
C PAL16A4 AND PAL16A4 FOR THE FUNCTION TABLE
IMPLICIT INTEGER (A-Z)
INTEGER ISYM(8,20),ISYM1(8,20),IBUF(8,20),IVECT(20),IVECTP(20)
LOGICAL LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LXNOR,
1 LFIX,LPHAS1(20),LBUF(20),LCLOCK,NREG,TOR,FXOR,FXNOR,TAND,
2 LPHASB,LPHASB
COMMON LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LXNOR
COMMON /PGE/ IPAGE(80,20C)
DATA L/'L'/,H/'H'/,X/'X'/,Z/'Z'/
C GET OUTPUT PIN AN (WHERE N=0,1,2,3)
CALL GETSYM(LBUF,IBUF,1,IC1,IL1,LFIX)
CALL MATCH(IINP,IBUF,ISYM1)
ITESTA=IVECT(IINP)
LPHASA = ( ( LBUF(1) ).AND.( LPHAS1(IINP) ).OR.
1 (.NOT.LBUF(1) ).AND.(.NOT.LPHAS1(IINP) ) )
C GET REGISTERED FEED BACK VALUES
IF(NREG) GO TO 5
CALL MATCH(IIFB,IBUF,ISYM)
IF( IIFB.EQ.14.OR.IIFB.EQ.15.OR.IIFB.EQ.16.OR.IIFB.EQ.17 )
1 ITESTA=IVECTP(IINP)
5 IF( (.NOT.LPHASA).AND.ITESTA.EQ.L ) GO TO 10
IF( (.NOT.LPHASA).AND.ITESTA.EQ.H ) GO TO 15
GO TO 20
10 ITESTA=H
GO TO 20
15 ITESTA=L
20 IF( (.NOT.LRIGHT) ) GO TO 25
ITEST=ITESTA
RETURN
C SAVE THE FIXED SYMBOL OPERATORS
25 TOR = (LOR.AND.(.NOT.LXOR))
FXOR = (LXOR)
FXNOR = (LXNOR)
TAND = (LAND.AND.(.NOT.LXNOR))
C GET INPUT BN (WHERE N=0,1,2,3)
CALL GETSYM(LBUF,IBUF,1,IC1,IL1,LFIX)
CALL MATCH(IINP,IBUF,ISYM1)
ITESTB=IVECT(IINP)
LPHASB = ( ( LBUF(1) ).AND.( LPHAS1(IINP) ).OR.
1 (.NOT.LBUF(1) ).AND.(.NOT.LPHAS1(IINP) ) )
IF( (.NOT.LPHASB).AND.ITESTB.EQ.L ) GO TO 30
IF( (.NOT.LPHASB).AND.ITESTB.EQ.H ) GO TO 35
GO TO 40
30 ITESTB=H
GO TO 40

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PAL15960
PAL15970
PAL15980
PAL15990
PAL16000
PAL16010
PAL16020
PAL16030
PAL16040
PAL16050
PAL16060
PAL16070
PAL16080
PAL16090
PAL16100
PAL16110
PAL16120
PAL16130
PAL16140
PAL16150
PAL16160
PAL16170
PAL16180
PAL16190
PAL16200
PAL16210
PAL16220
PAL16230
PAL16240
PAL16250
PAL16260
PAL16270
PAL16280
PAL16290
PAL16300
PAL16310
PAL16320
PAL16330
PAL16340
PAL16350
PAL16360
PAL16370
PAL16380
PAL16390
PAL16400
PAL16410
PAL16420
PAL16430
PAL16440
PAL16450
PAL16460
PAL16470
PAL16480
PAL16490
PAL16500

```
35 ITESTB=L PAL16510
C EVALUATE THE FIXED SYMBOL EXPRESSION PAL16520
40 ITEST=L PAL16530
IF( (TOR).AND.(ITESTA,EQ,H.OR, ITESTB,EQ,H) ) ITEST=H PAL16540
IF( (TXOR).AND.((ITESTA,EQ,H.AND, ITESTB,NE,H).OR. PAL16550
1 (ITESTA,NE,H.AND, ITESTB,EQ,H) )) ITEST=H PAL16560
IF( (TXNOR).AND.((ITESTA,EQ, ITESTB).OR. PAL16570
1 (ITESTA,EQ,X.OR, ITESTB,EQ,X) )) ITEST=H PAL16580
IF( (IAND).AND.(ITESTA,NE,L.AND, ITESTB,NE,L) ) ITEST=H PAL16590
IF( (ITESTA,EQ,X.OR, ITESTA,EQ,Z).AND.( ITESTB,EQ,X) ) ITEST=X PAL16600
RETURN PAL16610
END PAL16620
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Listing 2. PALASM Source Code for 24 Series

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FILE: PAL24   FORTRAN   A   NSC TIME SHARING SERVICES VM/SP RELEASE 2.0

C**PALASM24**PALASM24**PALASM24**PALASM24**PALASM24**PALASM24**PALASM24**PAL00010
C   PALASM 24 - TRANSLATES SYMBOLIC EQUATIONS INTO PAL OBJECT   PAL00020
C   CODE FORMATTED FOR DIRECT INPUT TO STANDARD   PAL00030
C   PROM PROGRAMMERS.   PAL00040
C   INPUT:   PAL DESIGN SPECIFICATION ASSIGNED   PAL00050
C   TO RPD(1). OPERATION CODES ARE   PAL00060
C   ASSIGNED TO ROP(5).   PAL00070
C   OUTPUT:   ECHO, SIMULATION, AND FUSE PATTERN   PAL00080
C   ARE ASSIGNED TO PDF(6). HEX AND   PAL00090
C   BINARY PROGRAMMING FORMATS ARE   PAL00100
C   ASSIGNED TO PDF(6). PROMPTS AND   PAL00110
C   ERROR MESSAGES ARE ASSIGNED TO   PAL00120
C   PMS(6).   PAL00130
C   PART NUMBER: THE PAL PART NUMBER MUST APPEAR   PAL00140
C   IN COLUMN ONE OF LINE ONE,   PAL00150
C   PIN LIST:   24 SYMBOLIC PIN NAMES MUST APPEAR   PAL00160
C   STARTING ON LINE FIVE.   PAL00170
C   EQUATIONS:   STARTING FIRST LINE AFTER THE   PAL00180
C   PIN LIST IN THE FOLLOWING FORMS:   PAL00190
C   A = B*C + D   PAL00200
C   A := B*C + D   PAL00210
C   IF( A*B ) C = D + E   PAL00220
C   ALL CHARACTERS FOLLOWING ';' ARE   PAL00230
C   IGNORED UNTIL THE NEXT LINE.   PAL00240
C   BLANKS ARE IGNORED.   PAL00250
C   OPERATORS:   ( IN HIERARCHY OF EVALUATION )   PAL00260
C   ;   COMMENT FOLLOWS   PAL00270
C   /   COMPLEMENT   PAL00280
C   *   AND (PRODUCT)   PAL00290
C   +   OR (SUM)   PAL00300
C   :+   XOR (EXCLUSIVE OR)   PAL00310
C   ( )   CONDITIONAL THREE-STATE   PAL00320
C   =   EQUALITY   PAL00330
C   :=   REPLACED BY (AFTER CLOCK)   PAL00340
C   FUNCTION   L, H, X, Z, AND C ARE VALID   PAL00350
C   TABLE:   FUNCTION TABLE VECTOR ENTRIES.   PAL00360
C   REFERENCE:   A COMPLETE USERS GUIDE TO   PAL00370
C   DESIGNING WITH PALS USING PALASM   PAL00380
C   IS PROVIDED IN THE MONOLITHIC   PAL00390
C   MEMORIES PAL HANDBOOK.   PAL00400
C   PAL00410
C   PAL00420
C   PAL00430
C   PAL00440
C   PAL00450
C   PAL00460
C   PAL00470
C   PAL00480
C   PAL00490
C   PAL00500
C   PAL00510
C   PAL00520
C   PAL00530
C   PAL00540
C   PAL00550

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C
C
C      SUBROUTINES:  INITLZ,GETSYM,INCR,MATCH,IXLATE,      PAL00560
C                   ECHO,CAT,PINOUT,PLOT,HEX,TWEEK,      PAL00570
C                   BINR,SLIP,FANTOM,IODC2,IODC4,TEST,    PAL00580
C                   PLOTF,SUMCHK                          PAL00590
C
C      REV LEVEL:   02/12/82 (VAX/VMS VERSION)          PAL00600
C                   10/13/82 FAULT TESTING              PAL00610
C                   10/15/82 JEDEC FORMAT                PAL00620
C                   BY:I.M.BENGALI                       PAL00630
C
C      AUTHORS:     JOHN BIRKNER AND VINCENT COLI      PAL00640
C                   MONOLITHIC MEMORIES INC.            PAL00650
C                   1165 EAST ARQUES AVENUE             PAL00660
C                   SUNNYVALE, CALIFORNIA 94043         PAL00670
C                   (408) 739-3535                      PAL00680
C
C      FINE PRINT:  MONOLITHIC MEMORIES TAKES NO       PAL00690
C                   RESPONSIBILITY FOR THE OPERATION    PAL00700
C                   OR MAINTENANCE OF THIS PROGRAM.    PAL00710
C                   THE SOURCE CODE AS PRINTED HERE    PAL00720
C                   PRODUCED THE OBJECT CODE OF THE    PAL00730
C                   EXAMPLES IN THE APPLICATIONS       PAL00740
C                   SECTION ON A VAX/VMS 11/780        PAL00750
C                   COMPUTER AND A NATIONAL CSS IBM    PAL00760
C                   SYSTEM/370 FORTRAN IV (G).         PAL00770
C
C*****PAL00780
C                   PAL00790
C                   PAL00800
C                   PAL00810
C                   PAL00820
C*****PAL00830
C                   PAL00840
C                   PAL00850
C*****PAL00860
C                   PAL00870
C                   PAL00880
C                   PAL00890
C                   PAL00900
C
C      MAIN PROGRAM
C
C      IMPLICIT INTEGER (A-Z)
C      INTEGER IPAL (3), INAME (5), REST (72), PATNUM (80), TITLE (80), COMP (80),
1      ISYM (8,24), IBUF (8,24), JPROD (80)
C      LOGICAL LBLANK, LLEFT, LAND, LOR, LSLASH, LEQUAL, LRIGHT, L XOR, LFIRST,
1      LMATCH, LFUSES (40,80), LPHASE (24), LBUF (24), LPROD (80),
2      LSAME, LACT, LOPERR, LINP, LERR, LSA11, LSA01
C      INTEGER BEL
C      COMMON LBLANK, LLEFT, LAND, LOR, LSLASH, LEQUAL, LRIGHT, L XOR
C      COMMON /PGE/ IPAGE (80,200)
C      COMMON /LFUSES/LFUSES
C      COMMON /FTEST/ IFUNCT, IDESC, IEND
C      COMMON /LUNIT/ PMS, POP, PDF
C      DATA E/'E',O/'O',T/'T',P/'P',B/'B',D/'D',H/'H',S/'S',
1      L/'L',N/'N',C/'C',Q/'Q',U/'U',F/'F',Y/'Y'/
C      DATA BB/'B',CC/'C',DD/'D',EE/'E',FF/'F',II/'I',NN/'N',
1      OO/'O',PP/'P',RR/'R',SS/'S',TT/'T',UU/'U',JJ/'J'/
C      DATA BEL/Z070000000/
C
C
C      ASSIGNMENT OF DATA SET REFERENCES
C                   PAL01080
C                   PAL01090
C                   PAL01100

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C	RPD - PAL DESIGN SPECIFICATION (INPUT)	PAL01110
C	ROC - OPERATION CODE (INPUT)	PAL01120
C	POF - ECHO, PINOUT, TEST, AND PLOT (OUTPUT)	PAL01130
C	PDF - HEX AND BINARY FORMAT PROGRAM TAPES (OUTPUT)	PAL01140
C	PMS - PROMPTS AND ERROR MESSAGES (OUTPUT)	PAL01150
	WRITE(6,3)	PAL01160
	3 FORMAT(/,' PALASM VERSION 1.5 ')	PAL01170
	WRITE(6,1)	PAL01180
	1 FORMAT(/,' WHAT IS THE LOGICAL UNIT NUMBER FOR OUTPUT(6)?: ')	PAL01190
	READ(5,2) LUN	PAL01200
	2 FORMAT(I4)	PAL01210
	RPD=1	PAL01220
	ROC=5	PAL01230
	POF=6	PAL01240
	PDF=6	PAL01250
	PMS=10	PAL01260
	IFUNCT=0	PAL01270
	IDESC=0	PAL01280
C	INITIALIZE LSAME AND LACT TO FALSE (ACTIVE HIGH/LOW ERROR)	PAL01290
	LSAME=.FALSE.	PAL01300
	LACT=.FALSE.	PAL01310
C	INITIALIZE LOPERR TO FALSE (OUTPUT PIN ERROR)	PAL01320
	LOPERR=.FALSE.	PAL01330
C	READ IN FIRST 4 LINES OF PAL DESIGN SPECIFICATION	PAL01340
	READ(RPD,10) IPAL,INAME,REST,PATNUM,TITLE,COMP	PAL01350
-10	FORMAT(3A1,5A1,72A1,/,80A1,/,80A1,/,80A1)	PAL01360
C	READ IN PIN LIST (LINE 5) THROUGH THE END OF THE PAL DESIGN	PAL01370
C	SPECIFICATION	PAL01380
	DO 15 J=1,200	PAL01390
	READ(RPD,11,END=10) (IPAGE(I,J),I=1,80)	PAL01400
11	FORMAT(80A1)	PAL01410
C	CHECK FOR 'FUNCTION TABLE' AND SAVE ITS LINE NUMBER	PAL01420
	IF(IFUNCT.EQ.0 .AND. IPAGE(1,J).EQ.FF.AND.	PAL01430
1	IPAGE(2,J).EQ.UU.AND. IPAGE(3,J).EQ.NN.AND.	PAL01440
2	IPAGE(4,J).EQ.CC.AND. IPAGE(5,J).EQ.TT.AND.	PAL01450
3	IPAGE(6,J).EQ.II.AND. IPAGE(7,J).EQ.OO.AND.	PAL01460
4	IPAGE(8,J).EQ.NN.AND. IPAGE(10,J).EQ.TT.AND.	PAL01470
5	IPAGE(12,J).EQ.BB.AND. IPAGE(14,J).EQ.EE) IFUNCT=J	PAL01480
C	CHECK FOR 'DESCRIPTION' AND SAVE ITS LINE NUMBER	PAL01490
	IF(IDESC.EQ.0 .AND. IPAGE(1,J).EQ.DD.AND.	PAL01500
1	IPAGE(2,J).EQ.EE.AND. IPAGE(3,J).EQ.SS.AND.	PAL01510
2	IPAGE(4,J).EQ.CC.AND. IPAGE(5,J).EQ.RR.AND.	PAL01520
3	IPAGE(6,J).EQ.II.AND. IPAGE(7,J).EQ.PP.AND.	PAL01530
4	IPAGE(8,J).EQ.TT.AND. IPAGE(9,J).EQ.II.AND.	PAL01540
5	IPAGE(10,J).EQ.OO.AND. IPAGE(11,J).EQ.NN) IDESC=J	PAL01550
15	CONTINUE	PAL01560
C	SAVE THE LAST LINE NUMBER OF THE PAL DESIGN SPECIFICATION	PAL01570
16	IEND=J-1	PAL01580
	CALL INITLZ(INAME,ITYPE,LFUSES,IC,IL,IBLOW,IPCTR)	PAL01590
C	PRINT ERROR MESSAGE FOR INVALID PAL PART TYPE	PAL01600
	IF(ITYPE.NE.0) GO TO 17	PAL01610
	WRITE(PMS,18) IPAL,INAME	PAL01620
18	FORMAT(/,' PAL PART TYPE ',3A1,5A1,' IS INCORRECT')	PAL01630
	STOP	PAL01640
C	GET 24 PIN NAMES	PAL01650

```

17 DO 20 J=1,24
20 CALL GETSYN(LPHASE,ISYM,J,IC,IL)
   IF(.NOT.(LEQUAL.OR.LLEFT.OR.LAND.OR.LOR.OR.LRIGHT)) GO TO 24
   WRITE(PMS,23)
23   FORMAT(/, ' LESS THAN 24 PIN NAMES IN PIN LIST')
   STOP
24 ILE=IL
C   BYPASS FUSE PLOT ASSEMBLY IF HAL (H IN LINE 1, COLUMN 1)
   IF( IPAL(1),EQ.H ) GO TO 106
25 CALL GETSYN(LBUF,IBUF,1,IC,IL)
28   IF(.NOT.LEQUAL) GO TO 25
   ILL=IL
   CALL MATCH(IMATCH,IBUF,ISYM)
   IF( IMATCH,EQ.0 ) GO TO 100
C   CHECK FOR VALID POLARITY (ACTIVE LOW)
   LSAME = ( ( LPHASE(IMATCH)).AND.( LBUF(1)).OR.
1     (.NOT.LPHASE(IMATCH)).AND.(.NOT.LBUF(1)) )
   IF( ITYPE.NE.6.AND.(LSAME) ) LACT=.TRUE.
C   CHECK FOR VALID OUTPUT PIN
29   IF( (ITYPE,EQ.1.OR.ITYPE,EQ.7.OR.ITYPE,EQ.9.OR.ITYPE,EQ.9.OR.
1     ITYPE,EQ.10).AND.(IMATCH.LT.14.OR.IMATCH.GT.23) )
2     LOPERR=.TRUE.
1     IF( (ITYPE,EQ.2.OR.ITYPE,EQ.11.OR.ITYPE,EQ.12.OR.ITYPE,EQ.13
1     .OR.ITYPE,EQ.14).AND.(IMATCH.LT.15.OR.IMATCH.GT.22) )
2     LOPERR=.TRUE.
1     IF( ITYPE,EQ.3.AND.(IMATCH.LT.16.OR.IMATCH.GT.21) )
1     LOPERR=.TRUE.
1     IF( ITYPE,EQ.4.AND.(IMATCH.LT.17.OR.IMATCH.GT.20) )
1     LOPERR=.TRUE.
1     IF( (ITYPE,EQ.5.OR.ITYPE,EQ.6).AND.
1     (IMATCH.LT.18.OR.IMATCH.GT.19) ) LOPERR=.TRUE.
   IF( (LACT).OR.(LOPERR) ) GO TO 100
   I88PRO=(23-IMATCH)*8 + 1
C   START PAL20C1 ON PRODUCT LINE 32 (I88PRO=33)
   IF(INAME(3),EQ.C) I88PRO=33
   IC=0
30   CALL INCR(IC,IL)
   IF( .NOT.(LEQUAL.OR.LLEFT) ) GO TO 30
   LPROD(I88PRO)=.TRUE.
   IF(.NOT.LLEFT) CALL SLIP(LFUSES,I88PRO,ITYPE,IBLOW)
   DO 70 I8PRO=1,16
   IF( (LXOR).AND.I8PRO.NE.3 ) GO TO 70
   IPROD = I88PRO + I8PRO - 1
   LPROD(IPROD)=.TRUE.
   LFIRST=.TRUE.
50   ILL=IL
   CALL GETSYN(LBUF,IBUF,1,IC,IL)
   CALL MATCH(IMATCH,IBUF,ISYM)
C   CHECK FOR INVALID INPUT PIN
1   IF( ITYPE,EQ.1.AND.(IMATCH.GE.14.AND.IMATCH.LE.23) )
1     LIMP=.TRUE.
1   IF( ITYPE,EQ.2.AND.(IMATCH.GE.15.AND.IMATCH.LE.22) )
1     LIMP=.TRUE.
1   IF( ITYPE,EQ.3.AND.(IMATCH.GE.16.AND.IMATCH.LE.21) )
1     LIMP=.TRUE.

```

```

PAL01660
PAL01670
PAL01680
PAL01690
PAL01700
PAL01710
PAL01720
PAL01730
PAL01740
PAL01750
PAL01760
PAL01770
PAL01780
PAL01790
PAL01800
PAL01810
PAL01820
PAL01830
PAL01840
PAL01850
PAL01860
PAL01870
PAL01880
PAL01890
PAL01900
PAL01910
PAL01920
PAL01930
PAL01940
PAL01950
PAL01960
PAL01970
PAL01980
PAL01990
PAL02000
PAL02010
PAL02020
PAL02030
PAL02040
PAL02050
PAL02060
PAL02070
PAL02080
PAL02090
PAL02100
PAL02110
PAL02120
PAL02130
PAL02140
PAL02150
PAL02160
PAL02170
PAL02180
PAL02190
PAL02200

```

	IF(ITYPE,EQ.4.AND.(IMATCH,GE.17.AND,IMATCH,LE.20))	PAL02210
1	LINP=.TRUE.	PAL02220
	IF(ITYPE,EQ.5.AND.(IMATCH,EQ.18.OR,IMATCH,EQ.19))	PAL02230
1	LINP=.TRUE.	PAL02240
	IF(ITYPE,EQ.6.AND.(IMATCH,EQ.18.OR,IMATCH,EQ.19))	PAL02250
1	LINP=.TRUE.	PAL02260
	IF(ITYPE,EQ.7.AND.(IMATCH,EQ.14.OR,IMATCH,EQ.23))	PAL02270
1	LINP=.TRUE.	PAL02280
	IF(ITYPE,EQ.8.AND.(IMATCH,EQ.1.OR,IMATCH,EQ.13))	PAL02290
1	LINP=.TRUE.	PAL02300
	IF(ITYPE,EQ.9.AND.(IMATCH,EQ.1.OR,IMATCH,EQ.13))	PAL02310
1	LINP=.TRUE.	PAL02320
	IF(ITYPE,EQ.10.AND.(IMATCH,EQ.1.OR,IMATCH,EQ.13))	PAL02330
1	LINP=.TRUE.	PAL02340
	IF(ITYPE,EQ.11.AND.(IMATCH,EQ.15.OR,IMATCH,EQ.22))	PAL02350
1	LINP=.TRUE.	PAL02360
	IF(ITYPE,GE.12.AND.(IMATCH,EQ.1.OR,IMATCH,EQ.13))	PAL02370
1	LINP=.TRUE.	PAL02380
	ILL=IL	PAL02390
	IF(LINP) GO TO 100	PAL02400
	IF(IMATCH,EQ.0) GO TO 100	PAL02410
	IF(IMATCH,EQ.12) GO TO 64	PAL02420
	IF(.NOT.LFIRST) GO TO 50	PAL02430
	LFIRST=.FALSE.	PAL02440
	DO 56 I=1,40	PAL02450
	IBLOW = IBLOW + 1	PAL02460
56	LFUSES(I,IPROD)=.TRUE.	PAL02470
58	CALL IXLATE(IINPUT,LPHASE,IMATCH,LBUF,ITYPE)	PAL02480
	IF(IINPUT,LE.0) GO TO 60	PAL02490
	IBLOW = IBLOW - 1	PAL02500
	LFUSES(IINPUT,IPROD)=.FALSE.	PAL02510
	CALL PLOT(LBUF,IBUF,LFUSES,IPROD,TITLE,.FALSE.,ITYPE,	PAL02520
1	LPROD,IOP,IBLOW)	PAL02530
60	IF(LAND) GO TO 50	PAL02540
64	IF(.NOT.LRIGHT) GO TO 68	PAL02550
66	CALL INCR(IC,IL)	PAL02560
	IF(.NOT.LEQUAL) GO TO 66	PAL02570
68	IF(.NOT.(LOR.OR.LEQUAL)) GO TO 74	PAL02580
70	CONTINUE	PAL02590
74	ILL=IL	PAL02600
	CALL GETSYM(LBUF,IBUF,I,IC,IL)	PAL02610
	IF(LLEFT.OR.LEQUAL) GO TO 28	PAL02620
100	IF(ILL,EQ.IFUNCT.OR,ILL,EQ.IDESC.OR,ILL,EQ.IEND) GO TO 102	PAL02630
C	PRINT AN ERROR MESSAGE FOR AN UNRECOGNIZABLE SYMBOL	PAL02640
	ILERR=ILL+4	PAL02650
	WRITE(PMS,99) BEL	PAL02660
99	FORMAT(' ',A1)	PAL02670
	WRITE(PMS,101) (IBUF(I,I),I=1,8),ILERR,(IPAGE(I,ILL),I=1,80)	PAL02680
101	FORMAT('/', ' ERROR SYMBOL = ',B1,' IN LINE NUMBER ',I3,	PAL02690
1	/, ' ',80A1)	PAL02700
C	PRINT AN ERROR MESSAGE FOR ACTIVE HIGH/LOW ERRORS	PAL02710
	IF((LACT).AND.(.NOT.LOPERR)) WRITE(PMS,103) IPAL,INAME	PAL02720
103	FORMAT(' OUTPUT MUST BE INVERTED SINCE ',B1,B1,	PAL02730
1	' IS AN ACTIVE LOW DEVICE')	PAL02740
C	PRINT AN ERROR MESSAGE FOR AN INVALID OUTPUT PIN	PAL02750


```

      IF( (LOPERR).AND.IMATCH.NE.0 ) WRITE(PMS,105) IMATCH,IPAL,INAME
105  FORMAT(' THIS PIN, NUMBER ',I2,' IS AN INVALID OUTPUT PIN',
      1      ' FOR ',3A1,5A1)
C     PRINT AN ERROR MESSAGE FOR AN INVALID INPUT PIN
      IF(LINP) WRITE(PMS,115) IMATCH,IPAL,INAME
115  FORMAT(' THIS PIN NUMBER ',I2,' IS AN INVALID INPUT PIN',
      1      ' FOR ',3A1,5A1)
      STOP
102  CALL TWECK (ITYPE,LFUSES)
108  WRITE(6,106)
106  FORMAT(/,' OPERATION CODES:')
      WRITE(6,107)
107  FORMAT(/,' E=ECHO INPUT O=PINOUT T=SIMULATE P=PLOT B=BRIEF',
      1      '/,' C=CATALOG H=HEX S=SHORT L=BHLF N=BNPF ',
      2      '/,' Q=QUIT F=FAULT TESTING J=JEDEC FORMAT')
      WRITE(6,110)
110  FORMAT(/,' ENTER OPERATION CODE: ')
      READ(ROC,120) IOP
120  FORMAT(A1)
C     CALL IODC2
      IF(POF.NE.6) WRITE(POF,125)
125  FORMAT('1')
      IF(IOP.EQ.E) CALL ECHO(IPAL,INAME,REST,PATNUM,TITLE,COMP)
      IF(IOP.EQ.O) CALL PINOUT(IPAL,INAME,TITLE)
      IF(IOP.EQ.T) CALL TEST(LPHASE,LBUF,TITLE,IC,IL,ILE,ISYM,IBUF,
      1      ITYPE,IPCTR,LERR,ISAF,IPCTR1,.FALSE.,.FALSE.)
      IF(IOP.EQ.JJ) CALL PLOTF
C
      ISAF=0
      IF(IOP.EQ.F) GO TO 200
C
135  IF(IOP.EQ.P) CALL PLOT(LBUF,IBUF,LFUSES,IPROD,TITLE,.TRUE.,ITYPE,
      1      LPROD,IOP,IBLOW,IPCTR)
      IF(IOP.EQ.B) CALL PLOT(LBUF,IBUF,LFUSES,IPROD,TITLE,.TRUE.,ITYPE,
      1      LPROD,IOP,IBLOW,IPCTR)
      IF(IOP.EQ.H) CALL HEX(LFUSES,H)
      IF(IOP.EQ.S) CALL HEX(LFUSES,S)
      IF(IOP.EQ.L) CALL BINR(LFUSES,H,L)
      IF(IOP.EQ.N) CALL BINR(LFUSES,P,N)
      IF(IOP.EQ.C) CALL CAT
C     CALL IODC4
      IF(IOP.NE.Q) GO TO 108
      STOP
C
C     SETTING THE PARAMETERS FOR THE SAO/SAI TESTS
200  IPCTR=0
      CALL TEST(LPHASE,LBUF,TITLE,IC,IL,ILE,ISYM,IBUF,ITYPE,IPCTR,
      1      LERR,ISAF,IPCTR1,.FALSE.,.FALSE.)
      IPCTR=IPCTR
C     LOOPING FOR SAI TEST
DO 210 IPCTR1=1,IPCTR0
      LSA11=.TRUE.
      CALL TEST(LPHASE,LBUF,TITLE,IC,IL,ILE,ISYM,IBUF,ITYPE,IPCTR,
      1      LERR,ISAF,IPCTR1,LSA11,.FALSE.)
210  CONTINUE

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      ISA1=ISAF
C   LOOPING FOR SAO TEST
      DO 215 IPCTR1=1,IPCTRO
      LSAO1=.TRUE.
      CALL TEST(LPHASE,LBUF,TITLE,IC,IL,ILE,ISYN,IBUF,IYPE,IPCTR,
1          LERR,ISAF,IPCTR1,.FALSE.,LSAO1)
215 CONTINUE
      ISAO=ISAF-ISA1
      IFAULT=(ISAF*100)/(2*IPCTRO)
      WRITE(POF,220) ISAO
220 FORMAT(/,' NUMBER OF STUCK AT ONE (SA1) FAULTS ARE =',I3)
      WRITE(POF,225) ISAO
225 FORMAT(/,' NUMBER OF STUCK AT ZERO (SAO) FAULTS ARE =',I3)
      WRITE(POF,230) IFAULT
230 FORMAT(/,' PRODUCT IERM COVERAGE =',I3,'%',//)
      GO TO 135
C
      END
C
C*****
C
C THIS SUBROUTINE GENERATES JEDEC FORMATTED OUTPUT FOR INTERFACING
C WITH DATA I/O PROGRAMMER
      SUBROUTINE PLOTF
      IMPLICIT INTEGER (A-Z)
      LOGICAL LFUSES(40,80)
      INTEGER IPBUF(40),ZERO,ONE
      INTEGER ISUM(4),IADR,STX,ETX,IDEC(4),IPT,IINP,J1,J2
      INTEGER IDECIO(4),ISUMV(4),ISUMIO(4),BUFIO(40)
      COMMON /LUNIT/PMS,POF,PDF
      COMMON /IPT/IPT
      COMMON /LFUSES/LFUSES
      COMMON /SUM/ISUM,IDEC,IPBUF,BUFIO
      DATA ZERO/'0'/,ONE/'1'/
      IADR=0
      STX=2
      ETX=3
      ISUM(2)=0
      ISUM(4)=230
      WRITE(PDF,10) STX
10  FORMAT(' ',A1,'*FO*')
      DO 300 IPT=1,80
      DO 50 IINP=1,40
      IF(LFUSES(IINP,IPT)) IPBUF(IINP)=ONE
      IF(.NOT.(LFUSES(IINP,IPT))) IPBUF(IINP)=ZERO
50  CONTINUE
      IF(LFUSES(1,IPT)) GO TO 100
      IF(.NOT.LFUSES(2,IPT)) GO TO 250
100 IDEC(4)=IADR
      DO 150 J=1,3
      J1=5-J
      J2=4-J
      IDEC(J2)=IDEC(J1)/10
      IDEC(J1)=IDEC(J1)-10*IDEC(J2)

```

```

PAL03310
PAL03320
PAL03330
PAL03340
PAL03350
PAL03360
PAL03370
PAL03380
PAL03390
PAL03400
PAL03410
PAL03420
PAL03430
PAL03440
PAL03450
PAL03460
PAL03470
PAL03480
PAL03490
PAL03500
PAL03510
PAL03520
PAL03530
PAL03540
PAL03550
PAL03560
PAL03570
PAL03580
PAL03590
PAL03600
PAL03610
PAL03620
PAL03630
PAL03640
PAL03650
PAL03660
PAL03670
PAL03680
PAL03690
PAL03700
PAL03710
PAL03720
PAL03730
PAL03740
PAL03750
PAL03760
PAL03770
PAL03780
PAL03790
PAL03800
PAL03810
PAL03820
PAL03830
PAL03840
PAL03850

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      IDECIO(J1)=ICONV(IDEC(J1))
150 CONTINUE
      IDECIO(1)=ICONV(IDEC(1))
      CALL SUMCHK
      WRITE(PDF,201) IDECIO,IPBUF
201 FORMAT(' L',4A1,' ',10(4A1,' '),'*')
250 IADR=IADR+40
300 CONTINUE
      ISUMIO(1)=ICONV(ISUM(2)/16)
      ISUM(2)=MOD(ISUM(2),16)
      ISUMIO(2)=ICONV(ISUM(2))
      ISUMIO(3)=ICONV(ISUM(4)/16)
      ISUM(4)=MOD(ISUM(4),16)
      ISUMIO(4)=ICONV(ISUM(4))
      WRITE(PDF,400) ITR,ISUMIO
400 FORMAT(' *',A1,4A1,'*',/)
      RETURN
      END

C
C
C
      SUBROUTINE SUMCHK
      IMPLICIT INTEGER(A-Z)
      LOGICAL LFUSES(40,80)
      INTEGER IPBUF(40), BUFIO(40)
      INTEGER ISUM(4), IDEC(4)
      COMMON /IPT/IPT
      COMMON /LFUSES/ LFUSES
      COMMON /SUM/ ISUM, IDEC,IPBUF,BUFIO
      DO 50 J=1,40
      IF(LFUSES(J,IPT)) BUFIO(J)=49
      IF(.NOT.LFUSES(J,IPT)) BUFIO(J)=46
      ISUM(4)=ISUM(4)+BUFIO(J)
      IF(ISUM(4).GE.256) ISUM(2)=ISUM(2)+1
      ISUM(4)=MOD(ISUM(4),256)
50 CONTINUE
      DO 100 J=1,4
      ISUM(4)=ISUM(4)+IDEC(J)+46
      IF(ISUM(4).GE.256) ISUM(2)=ISUM(2)+1
      ISUM(4)=MOD(ISUM(4),256)
100 CONTINUE
      ISUM(4)=ISUM(4)+173
      ISUM(2)=ISUM(2)+1
      IF(ISUM(4).GE.256) ISUM(2)=ISUM(2)+1
      ISUM(4)=MOD(ISUM(4),256)
      RETURN
      END

C*****
C
      INTEGER FUNCTION ICONV(K)
      IMPLICIT INTEGER(A-Z)
      DATA A/'0'/,B/'1'/,C/'2'/,D/'3'/,E/'4'/,F/'5'/,G/'6'/,H/'7'/
      DATA I/'8'/,J/'9'/,X/'A'/,L/'B'/,H/'C'/,N/'D'/,O/'E'/,P/'F'/
      IF(K.EQ.0) ICONV=A
      IF(K.EQ.1) ICONV=B

```

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PAL03860
PAL03870
PAL03880
PAL03890
PAL03900
PAL03910
PAL03920
PAL03930
PAL03940
PAL03950
PAL03960
PAL03970
PAL03980
PAL03990
PAL04000
PAL04010
PAL04020
PAL04030
PAL04040
PAL04050
PAL04060
PAL04070
PAL04080
PAL04090
PAL04100
PAL04110
PAL04120
PAL04130
PAL04140
PAL04150
PAL04160
PAL04170
PAL04180
PAL04190
PAL04200
PAL04210
PAL04220
PAL04230
PAL04240
PAL04250
PAL04260
PAL04270
PAL04280
PAL04290
PAL04300
PAL04310
PAL04320
PAL04330
PAL04340
PAL04350
PAL04360
PAL04370
PAL04380
PAL04390
PAL04400

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IF(K,EQ,2) ICONV=C
IF(K,EQ,3) ICONV=L
IF(K,EQ,4) ICONV=E
IF(K,EQ,5) ICONV=F
IF(K,EQ,6) ICONV=G
IF(K,EQ,7) ICONV=H
IF(K,EQ,8) ICONV=I
IF(K,EQ,9) ICONV=J
IF(K,EQ,10) ICONV=X
IF(K,EQ,11) ICONV=L
IF(K,EQ,12) ICONV=M
IF(K,EQ,13) ICONV=N
IF(K,EQ,14) ICONV=O
IF(K,EQ,15) ICONV=P
RETURN
END
C*****
C
C
SUBROUTINE INITLZ(INAME,ITYPE,LFUSES,IC,IL,IBLOW,IPCTR)
THIS SUBROUTINE INITIALIZES VARIABLES AND MATCHES PAL PART
NUMBER WITH ITYPE
C
IMPLICIT INTEGER (A-Z)
INTEGER INAME(5),INFO(6,14)
LOGICAL LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LFUSES(40,80),
1 LMATCH,LXOR
COMMON LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR
COMMON /PGE/ IPAGE(80,200)
DATA INFO/
1 '1','2','L','1','0',1,
2 '1','4','L','8',,2,
3 '1','6','L','6',,3,
4 '1','8','L','4',,4,
5 '2','0','L','2',,5,
6 '2','0','C','1',,6,
7 '2','0','L','1','0',7,
8 '2','0','X','1','0',8,
9 '2','0','X','8',,9,
A '2','0','X','4',,10,
B '2','0','L','8',,11,
C '2','0','R','8',,12,
D '2','0','R','6',,13,
E '2','0','R','4',,14/
C INITIALIZE LFUSES ARRAY (FUSE ARRAY)
DO 20 J=1,80
DO 20 I=1,40
20 LFUSES(I,J)=.FALSE.
C INITIALIZE IBLOW (NUMBER OF FUSES BLOWN)
IBLOW=0
IPCTR=0
C INITIALIZE IC AND IL (COLUMN AND LINE POINTERS)
IC=0
IL=1
C INITIALIZE ITYPE (PAL PART TYPE)
ITYPE=0
PAL04410
PAL04420
PAL04430
PAL04440
PAL04450
PAL04460
PAL04470
PAL04480
PAL04490
PAL04500
PAL04510
PAL04520
PAL04530
PAL04540
PAL04550
PAL04560
PAL04570
PAL04580
PAL04590
PAL04600
PAL04610
PAL04620
PAL04630
PAL04640
PAL04650
PAL04660
PAL04670
PAL04680
PAL04690
PAL04700
PAL04710
PAL04720
PAL04730
PAL04740
PAL04750
PAL04760
PAL04770
PAL04780
PAL04790
PAL04800
PAL04810
PAL04820
PAL04830
PAL04840
PAL04850
PAL04860
PAL04870
PAL04880
PAL04890
PAL04900
PAL04910
PAL04920
PAL04930
PAL04940
PAL04950

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C      ITYPE IS ASSIGNED THE FOLLOWING VALUES FOR THESE PAL TYPES:      PAL04960
C      PAL12L10 = 1    PAL14L8 = 2    PAL16L6 = 3    PAL18L4 = 4      PAL04970
C      PAL20L2 = 5    PAL20C1 = 6    PAL20L10 = 7    PAL20X10 = 8    PAL04980
C      PAL20X8 = 9    PAL20X4 = 10    PAL20L8 = 11    PAL20R8 = 12    PAL04990
C      PAL20R6 = 13    PAL20R4 = 14      PAL05000
      DO 40 J=1,14      PAL05010
          LMATCH=.TRUE.      PAL05020
          DO 30 I=1,4      PAL05030
30      IF (INAME(I).NE.INFO(1,J)) LMATCH=.FALSE.      PAL05040
          IF (LMATCH) ITYPE=INFO(6,J)      PAL05050
          IF (LMATCH) GO TO 50      PAL05060
40 CONTINUE      PAL05070
      IF (ITYPE.EQ.0) RETURN      PAL05080
50 CALL INCR(IC,IL)      PAL05090
      RETURN      PAL05100
      END      PAL05110
C      PAL05120
C*****      PAL05130
C      PAL05140
      SUBROUTINE GETSYM(LPHASE,ISYM,J,IC,IL)      PAL05150
C      THIS SUBROUTINE GETS THE PIN NAME, / IF COMPLEMENT LOGIC, AND      PAL05160
C      THE FOLLOWING OPERATION SYMBOL IF ANY      PAL05170
      IMPLICIT INTEGER (A-Z)      PAL05180
      INTEGER ISYM(8,24)      PAL05190
      LOGICAL LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LPHASE(24)      PAL05200
      COMMON LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR      PAL05210
      COMMON /PGE/ IPAGE(80,200)      PAL05220
      DATA IBLANK/' '/      PAL05230
      IF (.NOT.(LLEFT.OR.LAND.OR.LOR.OR.LEQUAL.OR.LRIGHT)) GO TO 10      PAL05240
      CALL INCR(IC,IL)      PAL05250
10  LPHASE(J)=(.NOT.LSLASH)      PAL05260
      IF (LPHASE(J)) GO TO 15      PAL05270
      CALL INCR(IC,IL)      PAL05280
15  DO 20 I=1,8      PAL05290
20      ISYM(I,J)=IBLANK      PAL05300
25  DO 30 I=1,7      PAL05310
30      ISYM(I,J)=ISYM(I+1,J)      PAL05320
      ISYM(8,J)=IPAGE(IC,IL)      PAL05330
      CALL INCR(IC,IL)      PAL05340
      IF (LLEFT.OR.LBLANK.OR.LAND.OR.LOR.OR.LRIGHT.OR.LEQUAL) RETURN      PAL05350
      GO TO 25      PAL05360
      END      PAL05370
C      PAL05380
C*****      PAL05390
C      PAL05400
      SUBROUTINE INCR(IC,IL)      PAL05410
C      THIS SUBROUTINE INCREMENTS COLUMN AND LINE POINTERS      PAL05420
C      BLANKS AND CHARACTERS AFTER ':' ARE IGNORED      PAL05430
      IMPLICIT INTEGER (A-Z)      PAL05440
      LOGICAL LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LXOR1      PAL05450
      COMMON LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR      PAL05460
      COMMON /PGE/ IPAGE(80,200)      PAL05470
      COMMON /LUNIT/ PMS,POF,PDF      PAL05480
      DATA IBLANK/' ',LLEFT/' ',LAND/'*',LOR/'+',COMENT/';',      PAL05490
1      ISLASH/'/',IEQUAL/'=',IRIGHT/'',ICOLON/'/'      PAL05500

```

```

      LBLANK=.FALSE,
      LXOR=.FALSE,
      LXOR1=.FALSE,
10  IC=IC+1
      IF( IC.LE.79.AND.IPAGE(IC,IL).NE.COMENT ) GO TO 30
      IL=IL+1
      IF(IL.LE.200) GO TO 20
        WRITE(PMS,15)
15  FORMAT(/,' SOURCE FILE EXCEEDS 200 LINES OR MISSING',
1  ' DESCRIPTION OR FUNCTION TABLE KEY WORD')
      STOP
20  IC=0
      GO TO 10
30  IF(IPAGE(IC,IL).NE.IBLANK) GO TO 31
      LBLANK=.TRUE.
      GO TO 10
31  IF(IPAGE(IC,IL).NE.ICOLON) GO TO 32
      IF(LXOR) GO TO 33
      LXOR1=.TRUE.
      GO TO 10
33  LOR=.TRUE.
      RETURN
32  IF( .NOT. (IPAGE(IC,IL).EQ.IOR.AND. (LXOR1)) ) GO TO 34
      LXOR=.TRUE.
      GO TO 10
34  LLEFT = (IPAGE(IC,IL).EQ.ILEFT)
      LAND = (IPAGE(IC,IL).EQ.IAND)
      LOR = (IPAGE(IC,IL).EQ.IOR)
      LSLASH=(IPAGE(IC,IL).EQ.ISLASH)
      LEQUAL=(IPAGE(IC,IL).EQ.IEQUAL)
      LRIGHT=(IPAGE(IC,IL).EQ.IRIGHT)
      RETURN
      END
C
C*****
C
      SUBROUTINE MATCH(IMATCH,IBUF,ISYM)
C  THIS SUBROUTINE FINDS A MATCH BETWEEN THE PIN NAME IN THE EQUATION
C  AND THE PIN NAME IN THE PIN LIST OR FUNCTION TABLE PIN LIST
      IMPLICIT INTEGER (A-Z)
      INTEGER IBUF(8,24),ISYM(8,24)
      LOGICAL IMATCH
      IMATCH=0
      DO 20 J=1,24
        LMATCH=.TRUE.
        DO 10 I=1,8
          10  LMATCH=LMATCH.AND.(IBUF(I,1).EQ.ISYM(I,J))
          IF(LMATCH) IMATCH=J
20  CONTINUE
      RETURN
      END
C
C*****
C
      SUBROUTINE IXLATE(IINPUT,LPHASE,IMATCH,LBUF,ITYPE)

```

PAL05510
 PAL05520
 PAL05530
 PAL05540
 PAL05550
 PAL05560
 PAL05570
 PAL05580
 PAL05590
 PAL05600
 PAL05610
 PAL05620
 PAL05630
 PAL05640
 PAL05650
 PAL05660
 PAL05670
 PAL05680
 PAL05690
 PAL05700
 PAL05710
 PAL05720
 PAL05730
 PAL05740
 PAL05750
 PAL05760
 PAL05770
 PAL05780
 PAL05790
 PAL05800
 PAL05810
 PAL05820
 PAL05830
 PAL05840
 PAL05850
 PAL05860
 PAL05870
 PAL05880
 PAL05890
 PAL05900
 PAL05910
 PAL05920
 PAL05930
 PAL05940
 PAL05950
 PAL05960
 PAL05970
 PAL05980
 PAL05990
 PAL06000
 PAL06010
 PAL06020
 PAL06030
 PAL06040
 PAL06050


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COMMON /LUNIT/ PMS,POF,PDF
WRITE(PMS,13)
10 FORMAT(/,' THIS PALASM AIDS THE USER IN THE DESIGN AND',
1      ' PROGRAMMING OF THE',/, ' SERIES 24 PAL FAMILY. THE',
2      ' FOLLOWING OPTIONS ARE PROVIDED:',
3      /,' ECHO (E) - PRINTS THE PAL DESIGN',
4      ' SPECIFICATION',
5      ///,' PINOUT (O) - PRINTS THE PINOUT OF THE PAL',
6      ///,' SIMULATE (T) - EXERCISES THE FUNCTION TABLE',
7      ' VECTORS IN THE LOGIC',/, ' ',
8      ' EQUATIONS AND GENERATES TEST VECTORS',
9      ///,' PLO1 (P) - PRINTS THE ENTIRE FUSE PLOT')
WRITE(PMS,20)
20 FORMAT(/,' BRIEF (B) - PRINTS ONLY THE USED PRODUCT LINES',
1      ' OF THE FUSE PLOT',/, ' PHANTOM',
2      ' FUSES ARE OMITTED',
3      ///,' JEDEC (J) - GENERATES FUSE OUTPUT FOR DATA I/O',
4      ' PROGRAMMERS',
5      ///,' HEX (H) - GENERATES HEX PROGRAMMING FORMAT',
6      ///,' SHORT (S) - GENERATES HEX PROGRAMMING FORMAT',
7      ///,' BHLF (L) - GENERATES BHLF PROGRAMMING FORMAT',
8      ///,' BNPF (N) - GENERATES BNPF PROGRAMMING FORMAT',
9      ///,' CATALOG (C) - PRINTS THE PALASM CATALOG',
A      ///,' QUIT (Q) - EXIT PALASM',
B      ///,' FAULT (F) - FAULT TESTING')
RETURN
END
C
C*****
C
SUBROUTINE PINOUT(IPAL,INAME,TITLE)
THIS SUBROUTINE PRINTS THE PINOUT OF THE PAL
IMPLICIT INTEGER (A-Z)
INTEGER IPAL(3),INAME(5),TITLE(80),PIN(12,24),IIN(8,2)
COMMON /PGE/ IPAGE(80,200)
COMMON /LUNIT/ PMS,POF,PDF
DATA IBLANK/' ',ISLASH/'/'
DO 10 J=1,24
DO 5 I=1,12
5 PIN(I,J)=IBLANK
10 CONTINUE
15 DO 25 J=1,2
DO 20 I=1,8
20 IIN(I,J)=IBLANK
25 CONTINUE
IIN(2,1)=IPAL(1)
IIN(4,1)=IPAL(2)
IIN(6,1)=IPAL(3)
IIN(1,2)=INAME(1)
IIN(3,2)=INAME(2)
IIN(5,2)=INAME(3)
IIN(7,2)=INAME(4)
IIN(8,2)=INAME(5)
J=0
IL=0
PAL06610
PAL06620
PAL06630
PAL06640
PAL06650
PAL06660
PAL06670
PAL06680
PAL06690
PAL06700
PAL06710
PAL06720
PAL06730
PAL06740
PAL06750
PAL06760
PAL06770
PAL06780
PAL06790
PAL06800
PAL06810
PAL06820
PAL06830
PAL06840
PAL06850
PAL06860
PAL06870
PAL06880
PAL06890
PAL06900
PAL06910
PAL06920
PAL06930
PAL06940
PAL06950
PAL06960
PAL06970
PAL06980
PAL06990
PAL07000
PAL07010
PAL07020
PAL07030
PAL07040
PAL07050
PAL07060
PAL07070
PAL07080
PAL07090
PAL07100
PAL07110
PAL07120
PAL07130
PAL07140
PAL07150

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30 IC=0 PAL07160
   IL=IL+1 PAL07170
35 IC=IC+1 PAL07180
40 IF( IC.GT.80 ) GO TO 30 PAL07190
   IF( IPAGE(IC,IL).EQ.IBLANK ) GO TO 35 PAL07200
   J=J+1 PAL07210
   IF(J.GT.24) GO TO 60 PAL07220
   DO 55 I=1,12 PAL07230
     PIN(I,J)=IPAGE(IC,IL) PAL07240
     IC=IC+1 PAL07250
     IF( IC.GT.80 ) GO TO 40 PAL07260
     IF( IPAGE(IC,IL).EQ.IBLANK ) GO TO 40 PAL07270
55 CONTINUE PAL07280
60 DO 75 J=1,12 PAL07290
   II=0 PAL07300
65 II=II+1 PAL07310
   IF(II.EQ.13) GO TO 75 PAL07320
   IF( PIN(II,J).NE.IBLANK ) GO TO 65 PAL07330
   I=13 PAL07340
70 I=I-1 PAL07350
   II=II-1 PAL07360
   PIN(I,J)=PIN(II,J) PAL07370
   PIN(II,J)=IBLANK PAL07380
   IF(II.NE.1) GO TO 70 PAL07390
75 CONTINUE PAL07400
   WRITE(POF,76) TITLE PAL07410
76 FORMAT(/,' ',80A1) PAL07420
   WRITE(POF,78) ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR, PAL07430
   1 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR, PAL07440
   2 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR, PAL07450
   3 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR PAL07460
78 FORMAT(/,' ',18X,14A1,3X,14A1, PAL07470
   1 /,' ',18X,A1,13X,A1,1X,A1,13X,A1) PAL07480
   JJ=24 PAL07490
   DO 88 J=1,12 PAL07500
     WRITE(POF,80) ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR PAL07510
80 FORMAT(' ',15X,4A1,29X,4A1) PAL07520
     WRITE(POF,81) (PIN(I,J),I=1,12),ISTAR,J,ISTAR, PAL07530
     1 (IIN(I,1),I=1,8),ISTAR,JJ,ISTAR,(PIN(I,JJ),I=1,12) PAL07540
81 FORMAT(' ',12A1,3X,A1,12,A1,11X,8A1,10X,A1,12,A1,3X,12A1) PAL07550
     WRITE(POF,82) ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR PAL07560
82 FORMAT(' ',15X,4A1,29X,4A1) PAL07570
     WRITE(POF,84) ISTAR,(IIN(I,2),I=1,8),ISTAR PAL07580
84 FORMAT(' ',18X,A1,11X,8A1,10X,A1) PAL07590
     DO 86 II=1,2 PAL07600
       DO 85 I=1,8 PAL07610
85 IIN(I,II)=IBLANK PAL07620
86 CONTINUE PAL07630
       JJ=JJ-1 PAL07640
88 CONTINUE PAL07650
     WRITE(POF,90) ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR, PAL07660
     1 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR, PAL07670
     2 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR, PAL07680
     3 ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR,ISTAR PAL07690
90 FORMAT(' ',18X,31A1) PAL07700

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RETURN
END
C
C*****
C
SUBROUTINE PLOT(LBUF,IBUF,LFUSES,IPROD,TITLE,LDUMP,ITYPE,LPROD,
1 IOP,IBLOW)
C THIS SUBROUTINE PRODUCES THE FUSE PLOT
IMPLICIT INTEGER (A-Z)-
INTEGER IBUF(8,24),IOUT(64),ISAVE(80,40),TITLE(80),IDATA(40)
LOGICAL LBUF(24),LFUSES(40,80),LDUMP,LPROD(80)
INTEGER STX,ETX
COMMON /LUNIT/ PMS,POF,PDF
DATA ISAVE/3200*' ',IAND/'*',IOR/'+',ISLASH/'',
1 IDASH/'-',X/'X',IBLANK/' ',P/'P',B/'B',
2 D/'D',ZERO/'0',ONE/'1',FX/'0',FIDASH/'0'/
DATA STX/Z02000000,ETX/Z03000000/
IF(LDUMP) GO TO 58
IF(ISAVE(IPROD,1).NE.IBLANK) RETURN
IF(LBUF(1)) GO TO 5
DO 30 J=1,39
30 ISAVE(IPROD,J)=ISAVE(IPROD,J+1)
ISAVE(IPROD,40)=ISLASH
5 DO 20 I=1,8
IF( ISAVE(IPROD,1).NE.IBLANK ) RETURN
IF( IBUF(I,1).EQ.IBLANK ) GO TO 20
DO 10 J=1,39
10 ISAVE(IPROD,J)=ISAVE(IPROD,J+1)
ISAVE(IPROD,40)=IBUF(I,1)
20 CONTINUE
IF(ISAVE(IPROD,1).NE.IBLANK) RETURN
40 DO 50 J=1,39
50 ISAVE(IPROD,J)=ISAVE(IPROD,J+1)
ISAVE(IPROD,40)=IAND
RETURN
C PRINT FUSE PLOT
58 IF(IOP.EQ.D) GO TO 62
WRITE(POF,61) TITLE
61 FORMAT(/,' ',80A1,/,
1 ' 11 1111 1111 2222 2222 2233 3333 3333',/,
2 ' 0123 4567 8901 2345 6789 0123 4567 8901 2345 6789',/)
GO TO 64
C***** STX DETERMINES THE STARTING CHARACTER FOR DATA I/O FORMAT
62 WRITE(POF,63) SIX
63 FORMAT(' ',A1,'*L0000'/)
64 DO 100 I88PRO=1,73,8
DO 94 I8PRO=1,8
IPROD=I88PRO+I8PRO-1
ISAVE(IPROD,40)=IBLANK
DO 70 I=1,40
IF( ISAVE(IPROD,1).NE.IBLANK ) GO TO 70
DO 65 J=1,39
65 ISAVE(IPROD,J)=ISAVE(IPROD,J+1)
ISAVE(IPROD,40)=IBLANK
70 CONTINUE
PAL07710
PAL07720
PAL07730
PAL07740
PAL07750
PAL07760
PAL07770
PAL07780
PAL07790
PAL07800
PAL07810
PAL07820
PAL07830
PAL07840
PAL07850
PAL07860
PAL07870
PAL07880
PAL07890
PAL07900
PAL07910
PAL07920
PAL07930
PAL07940
PAL07950
PAL07960
PAL07970
PAL07980
PAL07990
PAL08000
PAL08010
PAL08020
PAL08030
PAL08040
PAL08050
PAL08060
PAL08070
PAL08080
PAL08090
PAL08100
PAL08110
PAL08120
PAL08130
PAL08140
PAL08150
PAL08160
PAL08170
PAL08180
PAL08190
PAL08200
PAL08210
PAL08220
PAL08230
PAL08240
PAL08250

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DO 75 I=1,24                                PAL08260
      IOUT(I+40)=ISAVE(IPROD,I)                PAL08270
75 CONTINUE                                  PAL08280
IF( ISAVE(IPROD,25).NE.IBLANK ) IOUT(64)=IDASH PAL08290
DO 80 I=1,40                                  PAL08300
      IOUT(I)=X                                PAL08310
      IF(LFUSES(I,IPROD)) IOUT(I)=IDASH        PAL08320
80 CONTINUE                                  PAL08330
CALL FANTOM(ITYPE,IOP,IOUT,IPROD,I8PRO)       PAL08340
IF(IOP.NE.D) GO TO 85                          PAL08350
K=0                                             PAL08360
81 DO 82 I=1,40                                PAL08370
      IF((IOUT(I).EQ.FX).OR.(IOUT(I).EQ.FIDASH)) GO TO 82 PAL08380
      K=K+1                                     PAL08390
      IF(IOUT(I).EQ.X) IDATA(K)=ZERO           PAL08400
      IF(IOUT(I).EQ.IDASH) IDATA(K)=ONE        PAL08410
82 CONTINUE                                  PAL08420
DO 83 I=1,40                                  PAL08430
      IF( (IOUT(I).EQ.X).OR.(IOUT(I).EQ.IDASH) ) GO TO 86 PAL08440
83 CONTINUE                                  PAL08450
GO TO 94                                       PAL08460
86 WRITE(PDF,34) IDATA                         PAL08470
84 FORMAT(' ',40(A1,' '))                     PAL08480
GO TO 94                                       PAL08490
85 IPROD=IPROD-1                               PAL08500
      IF( (IOP.EQ.P).OR.(IOP.EQ.B.AND.(LPROD(IPROD+1))) ) PAL08510
      WRITE(POF,90) IPROD,IOUT                PAL08520
90 FORMAT(' ',I2,10(' ',4A1),' ',24A1)        PAL08530
94 CONTINUE                                  PAL08540
      WRITE(POF,96)                             PAL08550
96 FORMAT(1X)                                  PAL08560
100 CONTINUE                                  PAL08570
      IF(IOP.NE.D) GO TO 105                    PAL08580
      WRITE(PDF,101) ETX                       PAL08590
101 FORMAT(' ',A1)                             PAL08600
      RETURN                                    PAL08610
105 WRITE(POF,110)                             PAL08620
110 FORMAT(/,                                  PAL08630
1' LEGEND: X : FUSE NOT BLOWN (L,N,0) - : FUSE BLOWN (H,P,1)' ) PAL08640
      IF(IOP.EQ.P) WRITE(POF,111)              PAL08650
111 FORMAT(                                     PAL08660
1'      0 : PHANTOM FUSE (L,N,0) 0 : PHANTOM FUSE (H,P,1)' ) PAL08670
      WRITE(POF,112) IBLOW                     PAL08680
112 FORMAT(/,' NUMBER OF FUSES BLOW = ',I4)    PAL08690
      WRITE(POF,113)                           PAL08700
113 FORMAT(//)                                PAL08710
      RETURN                                    PAL08720
      END                                       PAL08730
C                                             PAL08740
C*****PAL08750
C                                             PAL08760
SUBROUTINE HEX(LFUSES,IOP)                     PAL08770
C THIS SUBROUTINE GENERATES HEX PROGRAMMING FORMATS PAL08780
IMPLICIT INTEGER (A-Z)                         PAL08790
INTEGER ITEMP(30),ZTABL1(32),ZTABL2(16),ZCSUM(4) PAL08800

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C*****PAL09360
C
BLOCK DATA
  IMPLICIT INTEGER (A-Z)
  COMMON /BLK/ PR8X10(10,14),PRODB(8,11),PRODLN(40,7)
  DATA PR8X10/
1    4, 4, 4, 4, 4, 4, 4, 4, 4, 4,
2    3, 6, 5, 5, 5, 5, 5, 5, 6, 3,
3    3, 3, 7, 7, 8, 8, 7, 7, 3, 3,
4    3, 3, 3, 9,10,10, 9, 3, 3, 3,
5    3, 3, 3, 3, 1, 1, 3, 3, 3, 3,
6    2, 2, 2, 2, 1, 1, 3, 3, 3, 3,
7    11,11,11,11,11,11,11,11,11,11,
8    11,11,11,11,11,11,11,11,11,11,
9    11,11,11,11,11,11,11,11,11,11,
A    11,11,11,11,11,11,11,11,11,11,
B    3, 1, 1, 1, 1, 1, 1, 1, 1, 3,
C    3, 1, 1, 1, 1, 1, 1, 1, 1, 3,
D    3, 1, 1, 1, 1, 1, 1, 1, 1, 3,
E    3, 1, 1, 1, 1, 1, 1, 1, 1, 3/
  DATA PRODB/
1    1,1,1,1,1,1,1,1,
2    2,2,2,2,2,2,2,2,
3    3,3,3,3,3,3,3,3,
4    4,4,3,3,3,3,3,3,
5    5,5,3,3,3,3,3,3,
6    5,5,5,5,3,3,3,3,
7    6,6,6,6,3,3,3,3,
8    6,6,3,3,3,3,3,3,
9    7,7,7,7,7,7,3,3,
A    7,7,7,7,3,3,3,3,
B    1,1,1,1,3,3,3,3/
  DATA PRODLN/
1    40*1HX,
2    40*1HP,
3    40*1HN,
4    6*1HX,2*1HP,2*1HX,2*1HP,2*1HX,2*1HP,2*1HX,
4    2*1HP,2*1HX,2*1HP,2*1HX,2*1HP,2*1HX,2*1HP,
4    2*1HX,2*1HP,4*1HX,
5    10*1HX,2*1HP,2*1HX,2*1HP,2*1HX,2*1HP,2*1HX,
5    2*1HP,2*1HX,2*1HP,2*1HX,2*1HP,9*1HX,
6    14*1HX,2*1HP,2*1HX,2*1HP,2*1HX,2*1HP,2*1HP,2*1HX,
6    2*1HP,12*1HX,
7    18*1HX,2*1HP,2*1HX,2*1HP,16*1HX/
  END
C
C*****PAL09820
C
SUBROUTINE TWEAK(ITYPE,LFUSES)
C THIS SUBROUTINE TWEAKS LFUSES (THE PROGRAMMING FUSE PLOT)
C FOR HIGH AND LOW PHANTOM FUSES
C IMPLICIT INTEGER (A-Z)
  LOGICAL LFUSES(40,80),LBLANK,LLEFT,LAND,LOR,LSLASH,
1    LEQUAL,LRIGHT,LXOR
  COMMON LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR

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COMMON /BLK/ PR8X10(10,14),PRODB(8,11),PRODLN(40,7)
DATA P/'P'/,N/'N'/
FUSPTR=1
DO 30 OUTPUT=1,10
  GRTYPE=PR8X10(OUTPUT,ITYPE)
  DO 30 PRLINE=1,8
    LNTYPE=PRODB(PRLINE,GRTYPE)
    DO 20 COL=1,40
      IF(PRODLN(COL,LNTYPE).EQ.P)
        LFUSES(COL,FUSPTR)=.TRUE.
      IF(PRODLN(COL,LNTYPE).EQ.N)
        LFUSES(COL,FUSPTR)=.FALSE.
    CONTINUE
    FUSPTR=FUSPTR+1
  30 CONTINUE
  RETURN
  END
C
C*****
C
SUBROUTINE BINR(LFUSES,H,L)
THIS SUBROUTINE GENERATES BINARY PROGRAMMING FORMATS
IMPLICIT INTEGER (A-Z)
INTEGER ITEMP(5,10)
LOGICAL LFUSES(40,80)
COMMON /LUNIT/ PMS,PDF,PDF
WRITE(PDF,10)
10 FORMAT(//,'
DO 20 I=1,41,40
INC=I-1
DO 20 IPROD=1,8
DO 20 J=1,31,10
DO 15 K=1,10
  IINPUT=J*K-1
  ITEMP(1,K)=L
  ITEMP(2,K)=L
  ITEMP(3,K)=L
  ITEMP(4,K)=L
  ITEMP(5,K)=L
  ISUM3=IPROD+INC
  IF(LFUSES(IINPUT,ISUM3 + 0 )) ITEMP(5,K)=H
  IF(LFUSES(IINPUT,ISUM3 + 8 )) ITEMP(4,K)=H
  IF(LFUSES(IINPUT,ISUM3 + 16 )) ITEMP(3,K)=H
  IF(LFUSES(IINPUT,ISUM3 + 24 )) ITEMP(2,K)=H
  IF(LFUSES(IINPUT,ISUM3 + 32 )) ITEMP(1,K)=H
15 CONTINUE
20 WRITE(PDF,30) ITEMP
30 FORMAT(' ',10('B',SA1,'F '))
WRITE(PDF,10)
RETURN
END
C
C*****
C
SUBROUTINE SLIP(LFUSES,188PRO,ITYPE,IBLOW)

```

PAL09910
 PAL09920
 PAL09930
 PAL09940
 PAL09950
 PAL09960
 PAL09970
 PAL09980
 PAL09990
 PAL10000
 PAL10010
 PAL10020
 PAL10030
 PAL10040
 PAL10050
 PAL10060
 PAL10070
 PAL10080
 PAL10090
 PAL10100
 PAL10110
 PAL10120
 PAL10130
 PAL10140
 PAL10150
 PAL10160
 PAL10170
 PAL10180
 PAL10190
 PAL10200
 PAL10210
 PAL10220
 PAL10230
 PAL10240
 PAL10250
 PAL10260
 PAL10270
 PAL10280
 PAL10290
 PAL10300
 PAL10310
 PAL10320
 PAL10330
 PAL10340
 PAL10350
 PAL10360
 PAL10370
 PAL10380
 PAL10390
 PAL10400
 PAL10410
 PAL10420
 PAL10430
 PAL10440
 PAL10450

C		PAL11010
	SUBROUTINE IODC2	PAL11020
C*****	THIS ROUTINE IS OPTIONAL, IT MAY BE USED TO TURN PERIPHERALS ON	PAL11030
	IMPLICIT INTEGER (A-Z)	PAL11040
	INTEGER BEL,DC2	PAL11050
	COMMON /LUNIT/ PMS,POF,PDF	PAL11060
	DATA BEL/Z07000000/,DC2/Z22000000/	PAL11070
	WRITE(PDF,10) DC2,BEL	PAL11080
10	FORMAT(' ',2A1)	PAL11090
	RETURN	PAL11100
	END	PAL11110
C		PAL11120
C*****	*****	PAL11130
C		PAL11140
	SUBROUTINE IODC4	PAL11150
C*****	THIS ROUTINE IS OPTIONAL, IT MAY BE USED TO TURN PERIPHERALS OFF	PAL11160
	IMPLICIT INTEGER (A-Z)	PAL11170
	INTEGER BEL,DC3,DC4	PAL11180
	DATA BEL/Z07000000/,DC3/Z23000000/,DC4/Z24000000/	PAL11190
	WRITE(PDF,10) BEL,DC3,DC4	PAL11200
10	FORMAT(' ',3A1)	PAL11210
	RETURN	PAL11220
	END	PAL11230
C		PAL11240
C*****	*****	PAL11250
C		PAL11260
	SUBROUTINE TEST(LPHASE,LBUF,TITLE,IC,IL,ILE,ISYM,IBUF,ITYPE,	PAL11270
1	IPCTR,LERR,ISAF,IPCTR1,LSA11,LSA01)	PAL11280
C	THIS SUBROUTINE PERFORMS THE FUNCTION TABLE SIMULATION	PAL11290
C	AND GENERATES TEST VECTORS	PAL11300
	IMPLICIT INTEGER (A-Z)	PAL11310
	INTEGER ISYM(8,24),ISYM1(8,24),IBUF(8,24),IVECT(24),IVECTP(24),	PAL11320
1	ISTATE(24),ISTATT(24),IPIN(24),TITLE(80),IPCTR	PAL11330
	LOGICAL LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR,LSAME,	PAL11340
1	XORFND,LERR,LPHASE(24),LPHAS1(24),LBUF(24),LOUT(24),	PAL11350
2	LOUTP(24),LCLOCK,LPRST,LCTRST,LENABL(24),NREG,	PAL11360
3	LSA11,LSA12,LSA01,LSA02	PAL11370
	INTEGER BEL	PAL11380
	COMMON LBLANK,LLEFT,LAND,LOR,LSLASH,LEQUAL,LRIGHT,LXOR	PAL11390
	COMMON /PGE/ IPAGE(80,200)	PAL11400
	COMMON /LUNIT/ PMS,POF,PDF	PAL11410
	COMMON /FTEST/ IFUNCT,IDESC,IEND	PAL11420
	DATA IDASH/'-'/,L/'L'/,H/'H'/,X/'X'/,C/'C'/,Z/'Z'/,NO/'O'/,	PAL11430
1	N1/'1'/,ERR/'?'/,IBLANK/' '/,COMENT/';'/	PAL11440
	DATA BEL/Z07000000/	PAL11450
C	PRINT AN ERROR MESSAGE IF NO FUNCTION TABLE IS SUPPLIED	PAL11460
	IF(IFUNCT.NE.0) GO TO 3	PAL11470
	WRITE(PMS,2)	PAL11480
2	FORMAT(/,' FUNCTION TABLE MUST BE SUPPLIED IN ORDER TO PERFORM',	PAL11490
1	' SIMULATION')	PAL11500
	RETURN	PAL11510
C	PRINT TITLE	PAL11520
3	IF((.NOT.LSA11).AND.(.NOT.LSA01)) WRITE(POF,4) TITLE	PAL11530
4	FORMAT(/,' ',80A1,/)	PAL11540
C	INITIALIZE LERR (FUNCTION TABLE ERROR FLAG) TO NO ERROR	PAL11550


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LERR=,FALSE.
C INITIALIZE NERR (NUMBER OF FUNCTION TABLE ERRORS) TO NO ERROR PAL11560
NERR=0 PAL11570
C SET THE STARTING POINT OF THE FUNCTION TABLE TO COLUMN 0 PAL11580
C AND IFUNCT + 1 PAL11590
IC=0 PAL11600
IL=IFUNCT + 1 PAL11610
C INITIALISE SA1/SA0 PARAMETERS PAL11620
IPCTR3=0 PAL11630
IEQN=0 PAL11640
IPCTR=0 PAL11650
C INITIALIZE ITRST (THREE-STATE ENABLE FUNCTION TABLE PIN NUMBER) PAL11660
ITRST=0 PAL11670
C MAKE A DUMMY CALL TO INCR PAL11680
CALL INCR(IC,IL) PAL11690
C GET THE FUNCTION TABLE PIN LIST (UP TO 22) PAL11700
C GO ONE MORE THAN MAX TO LOOK FOR DASHED LINE PAL11710
DO 10 I=1,23 PAL11720
CALL GETSYM(LPHAS1,ISYM1,I,IC,IL) PAL11730
DO 5 J=1,8 PAL11740
5 IBUF(J,1)=ISYM1(J,I) PAL11750
IF(IBUF(8,1).EQ.IDASH) GO TO 12 PAL11760
CALL MATCH(IMATCH,IBUF,ISYM) PAL11770
IF(IMATCH.NE.0) GO TO 7 PAL11780
WRITE(PMS,6) (IBUF(J,1),J=1,8) PAL11790
6 FORMAT(/,' FUNCTION TABLE PIN LIST ERROR AT', 8A1) PAL11800
RETURN PAL11810
7 LOUT(I)=,FALSE. PAL11820
ISTATT(I)=X PAL11830
IVECTP(I)=X PAL11840
C IF APPROPRIATE PAL TYPE, REMEMBER LOCATION OF CLOCK AND THREE-STATE PAL11850
C ENABLE PIN IN FUNCTION TABLE PIN LIST PAL11870
IF(,NOT.(ITYPE,EQ,8,OR,ITYPE,EQ,9,OR,ITYPE,EQ,10,OR. PAL11880
1 ITYPE,EQ,12,OR,ITYPE,EQ,13,OR,ITYPE,EQ,14) ) GO TO 10 PAL11890
IF(IMATCH,EQ,1) ICLOCK=I PAL11900
IF(IMATCH,EQ,13) ITRST=I PAL11910
10 IPIN(I)=IMATCH PAL11920
C ALL SIGNAL NAMES FOR THE FUNCTIONAL TEST HAVE BEEN READ IN PAL11930
C ADJUST COUNT PAL11940
12 IMAX=I-1 PAL11950
NVECT=0 PAL11960
C PAL11970
C*****START OF MAIN LOOP FOR SIMULATION***** PAL11980
C PAL11990
C PAL12000
90 IPCTR2=0 PAL12010
IEQN=0 PAL12020
IPCTR3=0 PAL12030
LSA12=,FALSE. PAL12040
LSA02=,FALSE. PAL12050
C PAL12060
NVECT=NVECT+1 PAL12070
IC1=0 PAL12080
IL1=ILE PAL12090
C GO PASSED COMMENT LINES PAL12100

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23	IF(IPAGE(1,IL).NE.COMENT) GO TO 24	PAL12110
	IL=IL+1	PAL12120
	GO TO 23	PAL12130
24	CONTINUE	PAL12140
C	GETS VECTORS FROM FUNCTION TABLE	PAL12150
	DO 20 I=1,IMAX	PAL12160
	IF(IPAGE(IC,IL).EQ.IBLANK) GO TO 21	PAL12170
	GO TO 22	PAL12180
21	IC=IC+1	PAL12190
	IF(IPAGE(IC,IL).EQ.IBLANK) GO TO 21	PAL12200
22	I Vect(I)=IPAGE(IC,IL)	PAL12210
	IC=IC+1	PAL12220
20	CONTINUE	PAL12230
C	ADVANCE LINE COUNT TO SKIP FUNCTION TABLE COMMENTS	PAL12240
	IL=IL+1	PAL12250
	IC=1	PAL12260
	IF(I Vect(I).EQ.IDASH) GO TO 95	PAL12270
C	CHECK FOR VALID FUNCTION TABLE VALUES (L,H,X,Z,C)	PAL12280
	DO 11 I=1,IMAX	PAL12290
	IF(I Vect(I).EQ.L.OR.I Vect(I).EQ.H.OR.I Vect(I).EQ.X.OR.	PAL12300
1	I Vect(I).EQ.Z.OR.I Vect(I).EQ.C) GO TO 11	PAL12310
	WRITE(PMS,8) I Vect(I),N Vect	PAL12320
8	FORMAT(/,' ',A1,' IS NOT AN ALLOWED FUNCTION TABLE ENTRY',	PAL12330
1	' IN VECTOR ',I3)	PAL12340
	RETURN	PAL12350
11	CONTINUE	PAL12360
C	INITIALIZE CLOCK AND THREE-STATE ENABLE FLAGS	PAL12370
	LCLOCK=.FALSE.	PAL12380
	LCTRST=.TRUE.	PAL12390
	LPTRST=.TRUE.	PAL12400
	DO 13 I=1,IMAX	PAL12410
13	LENABL(I)=.TRUE.	PAL12420
C	INITIALIZE NREG (NOT REGISTERED OUTPUT) TO FALSE	PAL12430
	NREG=.FALSE.	PAL12440
C	INITIALIZE ISTATE ARRAY TO ALL X'S	PAL12450
	DO 15 I=1,24	PAL12460
15	ISTATE(I)=X	PAL12470
C	CHECK IF THIS PAL TYPE HAS REGISTERS	PAL12480
	IF(.NOT. (ITYPE.EQ.8.OR.ITYPE.EQ.9.OR.ITYPE.EQ.10.OR.	PAL12490
1	ITYPE.EQ.12.OR.ITYPE.EQ.13.OR.ITYPE.EQ.14)) GO TO 25	PAL12500
C	CHECK CLOCK AND THREE-STATE ENABLE PINS AND CHANGE FLAG IF NEEDED	PAL12510
	IF(I Vect(ICLOCK).EQ.C) LCLOCK=.TRUE.	PAL12520
	IF(ITRST.EQ.0) GO TO 25	PAL12530
	LSAME=((LPHASE(I3)).AND.(LPHAS1(ITRST)).OR.	PAL12540
1	(.NOT.LPHASE(I3)).AND.(.NOT.LPHAS1(ITRST)))	PAL12550
	IF(I Vect(ITRST).EQ.L.AND.(.NOT.LSAME).OR.	PAL12560
1	I Vect(ITRST).EQ.H.AND.(LSAME)) LPTRST=.FALSE.	PAL12570
	IF(LPTRST) GO TO 25	PAL12580
C	DISABLE REGISTERED OUTPUTS IF APPROPRIATE	PAL12590
	DO 46 I=1,IMAX	PAL12600
	J=IPIN(I)	PAL12610
	IF(J.EQ.17.OR.J.EQ.18.OR.J.EQ.19.OR.J.EQ.20) LENABL(I)=.FALSE.	PAL12620
	IF((ITYPE.EQ.8.OR.ITYPE.EQ.9.OR.ITYPE.EQ.12.OR.	PAL12630
1	ITYPE.EQ.13).AND.(J.EQ.16.OR.J.EQ.21)) LENABL(I)=.FALSE.	PAL12640
	IF((ITYPE.EQ.8.OR.ITYPE.EQ.9.OR.ITYPE.EQ.12).AND.	PAL12650

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1          (J,EQ.15,OR,J,EQ.22) )          LENABL(I)=.FALSE. PAL12660
      IF( ITYPE,EQ.8,AND,(J,EQ.14,OR,J,EQ.23) )  LENABL(I)=.FALSE. PAL12670
46 CONTINUE                                     PAL12680
C                                                PAL12690
C*****SCAN THROUGH THE LOGIC EQUATIONS***** PAL12700
C                                                PAL12710
C      MAKE A DUMMY CALL TO INCR                PAL12720
25 CALL INCR(IC1,IL1)                          PAL12730
26 CALL GETSYM(LBUF,IBUF,1,IC1,IL1)           PAL12740
      IF(LLEFT) GO TO 29                       PAL12750
27 IF(.NOT.LEQUAL) GO TO 26                  PAL12760
C                                                PAL12770
      IF(LEQUAL) IEQN=IEQN+1                  PAL12780
C                                                PAL12790
C      EVALUATE CONDITIONAL THREE-STATE PRODUCT LINE PAL12800
29 IF(LEQUAL) GO TO 35                       PAL12810
      NREG=.TRUE.                             PAL12820
33 CALL GETSYM(LBUF,IBUF,1,IC1,IL1)           PAL12830
      CALL MATCH(IINP,IBUF,ISYM1)             PAL12840
C      CHECK FOR GND, VCC, /GND, OR /VCC IN CONDITIONAL THREE-STATE PAL12850
C      PRODUCT LINE                            PAL12860
      IF(IINP.NE.0) GO TO 32                  PAL12870
      CALL MATCH(IMATCH,IBUF,ISYM)           PAL12880
      ILL=IL1                                 PAL12890
      IF( IMATCH,EQ.12,AND,(LBUF(1)).OR.      PAL12900
1      IMATCH,EQ.24,AND,(.NOT.LBUF(1)) ) LCTRST=.FALSE. PAL12910
      IF( IINP,EQ.0,AND,IMATCH.NE.12,AND,IMATCH.NE.24 ) GO TO 100 PAL12920
      GO TO 34                                 PAL12930
32 ITEST=IVECT(IINP)                         PAL12940
      IF( ITEST,EQ.L,AND,( LPHAS1(IINP)).AND,( LBUF(1)) PAL12950
1,OR, ITEST,EQ.H,AND,( LPHAS1(IINP)).AND,(.NOT.LBUF(1)) PAL12960
2,OR, ITEST,EQ.H,AND,(.NOT.LPHAS1(IINP)).AND,( LBUF(1)) PAL12970
3,OR, ITEST,EQ.L,AND,(.NOT.LPHAS1(IINP)).AND,(.NOT.LBUF(1)) PAL12980
4 ) LCTRST=.FALSE.                            PAL12990
      IF(ITEST,EQ.X,OR,ITEST,EQ.Z) LCTRST=.FALSE. PAL13000
34 IF(LAND) GO TO 33                          PAL13010
      GO TO 27                                 PAL13020
C                                                PAL13030
C      EVALUATE THE LOGIC EQUATION              PAL13040
C                                                PAL13050
C      FIND PIN NUMBER OF THE OUTPUT VECTORS   PAL13060
C                                                PAL13070
35 IPCTR3=0                                    PAL13080
C                                                PAL13090
      CALL MATCH(IOUIP,IBUF,ISYM1)           PAL13100
C      FLAG FOR UNREGISTERED OUTPUTS          PAL13110
      CALL MATCH(IOUT,IBUF,ISYM)            PAL13120
      IF(ITYPE.LE.7,OR,ITYPE,EQ.11) NREG=.TRUE. PAL13130
      IF( (ITYPE,EQ.9,OR,ITYPE,EQ.10).AND,(IOUT,EQ.14,OR,IOUT,EQ.23) ) PAL13140
1      NREG=.TRUE.                             PAL13150
      IF( (ITYPE,EQ.10,OR,ITYPE,EQ.13,OR,ITYPE,EQ.14).AND. PAL13160
1      (IOUT,EQ.15,OR,IOUT,EQ.22) ) NREG=.TRUE. PAL13170
      IF( (ITYPE,EQ.10,OR,ITYPE,EQ.14).AND,(IOUT,EQ.16,OR,IOUT,EQ.21) ) PAL13180
1      NREG=.TRUE.                             PAL13190
      ILL=IL1                                 PAL13200

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	IF (IOUTP.EQ.0) GO TO 100	PAL13210
	IF (NREG) LENABL (IOUTP) =LCTRST	PAL13220
	LOJT (IOUTP) =.TRUE.	PAL13230
	IF (.NOT,LCTRST) LOJT (IOUTP) =.FALSE.	PAL13240
	LCTRST=.TRUE.	PAL13250
	LOUTP (IOUTP) =LBUF (1)	PAL13260
C	DETERMINE PRODUCT TERM AND EVENTUALLY SUM FOR OUTPUT KEEPING	PAL13270
C	TRACK TO SEE IF AN XOR (EXCLUSIVE OR) HAS BEEN FOUND	PAL13280
	XORSUM=H	PAL13290
	XORFND=.FALSE.	PAL13300
	ISUM=L	PAL13310
C		PAL13320
28	IPCTR2=IPCTR2+1	PAL13330
	IPCTR3=IPCTR3+1	PAL13340
	IPCIR=IPCTR+1	PAL13350
C		PAL13360
	IPROD=H	PAL13370
30	ILL=IL1	PAL13380
	CALL GETSYM (LBUF,IBUF,1,IC1,IL1)	PAL13390
	CALL MATCH (IINP,IBUF,ISYM1)	PAL13400
	IF (IINP.NE.0) GO TO 47	PAL13410
	CALL MATCH (IMATCH,IBUF,ISYM)	PAL13420
	IF (IMATCH.NE.12.AND.IMATCH.NE.24) GO TO 100	PAL13430
C	TWEAK FOR GND AND VCC IN PRODUCT LINE	PAL13440
	IF (IMATCH.EQ.12) ITEST=L	PAL13450
	IF (IMATCH.EQ.24) ITEST=H	PAL13460
	IINP=23	PAL13470
	LPHAS1 (23) =.TRUE.	PAL13480
	GO TO 37	PAL13490
47	ITEST=IVECT (IINP)	PAL13500
C	GET REGISTERED FEED BACK VALUES	PAL13510
	IF (NREG) GO TO 37	PAL13520
	CALL MATCH (IIFB,IBUF,ISYM)	PAL13530
	IF ((ITYPE.EQ.8.OR.ITYPE.EQ.9.OR.ITYPE.EQ.10.OR.ITYPE.EQ.12.OR.	PAL13540
1	ITYPE.EQ.13.OR.ITYPE.EQ.14).AND.(IIFB.EQ.17.OR.IIFB.EQ.18.OR.	PAL13550
2	IIFB.EQ.19.OR.IIFB.EQ.20)) ITEST=IVECTP (IINP)	PAL13560
	IF ((ITYPE.EQ.8.OR.ITYPE.EQ.9.OR.ITYPE.EQ.12.OR.ITYPE.EQ.13).AND.	PAL13570
1	(IIFB.EQ.16.OR.IIFB.EQ.21)) ITEST=IVECTP (IINP)	PAL13580
	IF ((ITYPE.EQ.8.OR.ITYPE.EQ.9.OR.ITYPE.EQ.12).AND.	PAL13590
1	(IIFB.EQ.15.OR.IIFB.EQ.22)) ITEST=IVECTP (IINP)	PAL13600
	IF ((ITYPE.EQ.8.AND.(IIFB.EQ.14.OR.IIFB.EQ.23))	PAL13610
1	ITEST=IVECTP (IINP)	PAL13620
37	IF (ITEST.EQ.X.OR.ITEST.EQ.Z) ITEST=L	PAL13630
	IF (ITEST.EQ.L.AND.(LPHAS1 (IINP)) .AND.(LBUF (1))	PAL13640
1	.OR. ITEST.EQ.H.AND.(LPHAS1 (IINP)) .AND.(.NOT,LBUF (1))	PAL13650
2	.OR. ITEST.EQ.H.AND.(.NOT,LPHAS1 (IINP)) .AND.(LBUF (1))	PAL13660
3	.OR. ITEST.EQ.L.AND.(.NOT,LPHAS1 (IINP)) .AND.(.NOT,LBUF (1))	PAL13670
4) IPROD=L	PAL13680
C		PAL13690
	IF ((IPCTR2.EQ.IPCTR1).AND.(LSA11)) GO TO 110	PAL13700
C		PAL13710
38	IF (LAND) GO TO 30	PAL13720
C		PAL13730
	IF ((IPCTR2.EQ.IPCTR1).AND.(LSA01)) GO TO 120	PAL13740
C		PAL13750

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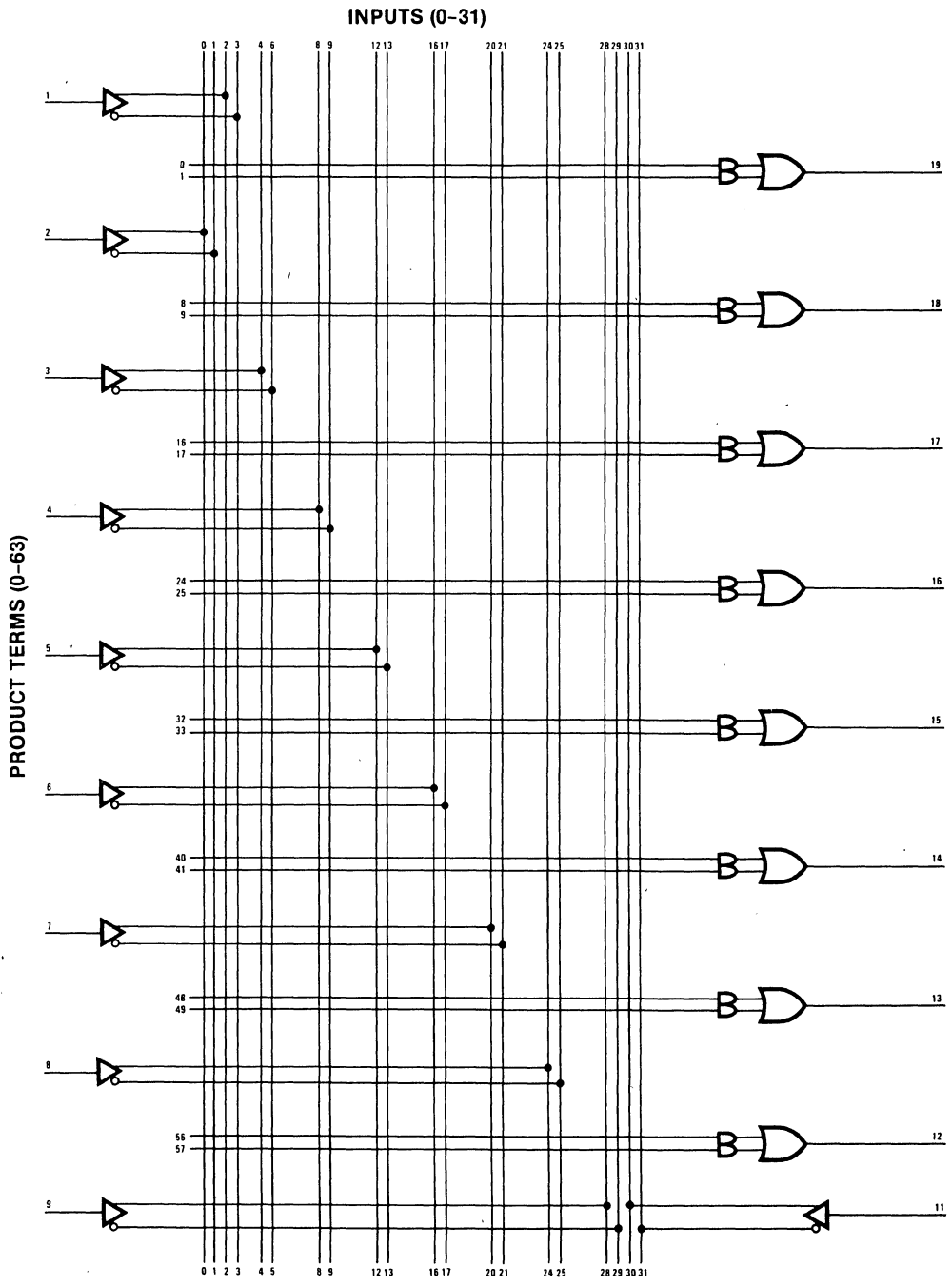
121 IF (ISUM, EQ, L, AND, IPROD, EQ, X) ISUM=X PAL13760
IF ( (LSUM, NE, H), AND, IPROD, EQ, H ) ISUM=H PAL13770
C CHECK FOR XOR (EXCLUSIVE OR) AND SAVE INTERMEDIATE VALUE PAL13780
IF (, NOI, LKOR) GO TO 31 PAL13790
XORSUM=ISUM PAL13800
XORFND=, TRUE. PAL13810
ISUM=L PAL13820
GO TO 26 PAL13830
31 IF (LOR) GO TO 28 PAL13840
IPCTR3=0 PAL13850
C IF END OF EQUATION HAS BEEN FOUND, DETERMINE FINAL SUM AND SAVE ITPAL13860
IF (, NOT, XORFND) ISTAT1 (IOUTP)=ISUM PAL13870
IF ( (XORFND), AND, ( (ISUM, EQ, L, AND, XORSUM, EQ, L), OR, PAL13880
1 (ISUM, EQ, H, AND, XORSUM, EQ, H) ) ISTAT1 (IOUTP)=L PAL13890
IF ( (XORFND), AND, ( (ISUM, EQ, H, AND, XORSUM, EQ, L), OR, PAL13900
1 (ISUM, EQ, L, AND, XORSUM, EQ, H) ) ISTAT1 (IOUTP)=H PAL13910
IF ( (XORFND), AND, (ISUM, EQ, X, OR, XORSUM, EQ, X) ) ISTAT1 (IOUTP)=X PAL13920
C REGISTER DOES NOT CHANGE STATE IF NO CLOCK PULSE IS RECEIVED PAL13930
IF ( (LCLOCK), OR, (NREG) ) GO TO 36 PAL13940
LSAME = ( ( LOUTP (IOUTP) ), AND, ( LPHAS1 (IOUTP) ), OR, PAL13950
1 (, NOT, LOUTP (IOUTP) ), AND, (, NOT, LPHAS1 (IOUTP) ) ) PAL13960
IF ( IVECTP (IOUTP), EQ, L, AND, ( LSAME ) ISTAT1 (IOUTP)=L PAL13970
IF ( IVECTP (IOUTP), EQ, H, AND, ( LSAME ) ISTAT1 (IOUTP)=H PAL13980
IF ( IVECTP (IOUTP), EQ, L, AND, (, NOT, LSAME ) ISTAT1 (IOUTP)=H PAL13990
IF ( IVECTP (IOUTP), EQ, H, AND, (, NOT, LSAME ) ISTAT1 (IOUTP)=L PAL14000
36 NREG=, FALSE. PAL14010
C CHECK IF ALL EQUATIONS HAVE BEEN PROCESSED BY COMPARING CURRENT PAL14020
LINE NUMBER WITH FUNCTION TABLE LINE NUMBER PAL14030
C IF (IDESC, NE, 0, AND, IL1, LT, IFUNCT, AND, IL1, LT, IDESC, OR, PAL14040
1 IDESC, EQ, 0, AND, IL1, LT, IFUNCT) GO TO 27 PAL14050
C DETERMINE OUTPUT LOGIC VALUES PAL14060
C COMPARE OUTPUTS TO SEE IF VECTOR AGREES WITH RESULTS PAL14070
DO 50 I=1, IMAX PAL14080
IF (, NOT, LOUT (I) ) GO TO 50 PAL14090
IF (ISTATT (I), EQ, X, AND, IVECT (I), EQ, X) GO TO 50 PAL14100
LSAME = ( ( LOUTP (I) ), AND, ( LPHAS1 (I) ), OR, PAL14110
1 (, NOI, LOUTP (I) ), AND, (, NOT, LPHAS1 (I) ) ) PAL14120
IMESS=40 PAL14130
IF (ISTATT (I), EQ, L, AND, IVECT (I), EQ, L, AND, (, NOT, LSAME) ) IMESS=41 PAL14140
IF (ISTATT (I), EQ, H, AND, IVECT (I), EQ, H, AND, (, NOT, LSAME) ) IMESS=42 PAL14150
IF (ISTATT (I), EQ, L, AND, IVECT (I), EQ, H, AND, ( LSAME) ) IMESS=42 PAL14160
IF (ISTATT (I), EQ, H, AND, IVECT (I), EQ, L, AND, ( LSAME) ) IMESS=41 PAL14170
IF ( ( LENABL (I) ), AND, IVECT (I), EQ, Z ) IMESS=43 PAL14180
IF ( (, NOT, LENABL (I) ), AND, (LOUT (I) ), AND, IVECT (I), NE, Z ) IMESS=44 PAL14190
IF (IMESS, NE, 40) LERR=, TRUE. PAL14200
C IF ( (, NOT, LERR), AND, ((LSA11), OR, (LSA01))) GO TO 50 PAL14210
IF ( (LERR), AND, ((LSA11), OR, (LSA01))) GO TO 115 PAL14230
C IF (IMESS, EQ, 41) WRITE (PMS, 41) NVECT, (ISYM1 (J, I), J=1, 8) PAL14240
41 FORMAT (/, ' FUNCTION TABLE ERROR IN VECTOR', I3, ' PIN = ', 8A1, PAL14260
1 ' EXPECT = H ACTUAL = L') PAL14270
IF (IMESS, EQ, 42) WRITE (PMS, 42) NVECT, (ISYM1 (J, I), J=1, 8) PAL14280
42 FORMAT (/, ' FUNCTION TABLE ERROR IN VECTOR', I3, ' PIN = ', 8A1, PAL14290
1 ' EXPECT = L ACTUAL = H') PAL14300

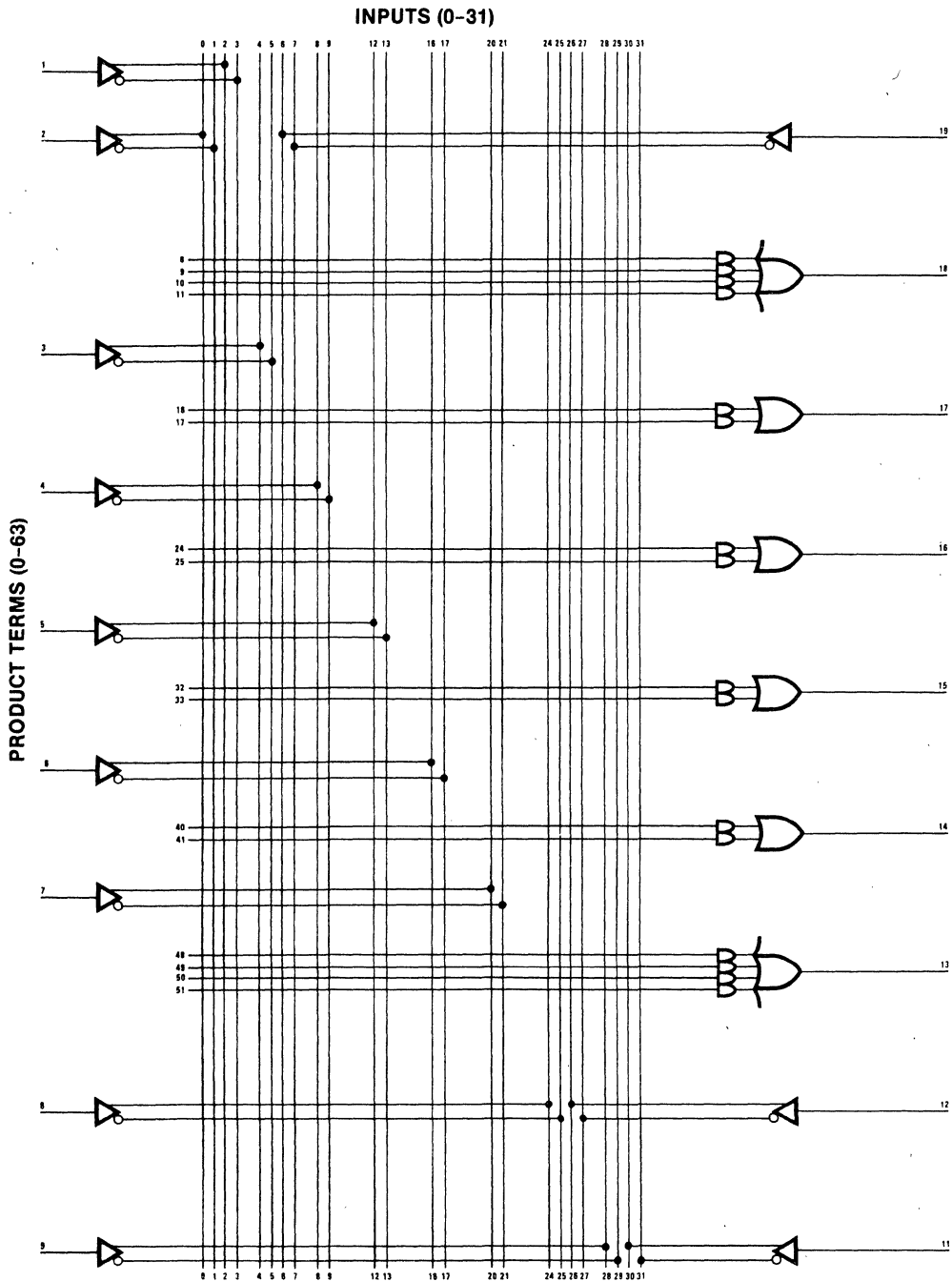
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	IF (IMESS.EQ.43) WRITE (PMS,43) NVECT, (ISYM1(J,I),J=1,8)	PAL14310
43	FORMAT(/,' FUNCTION TABLE ERROR IN VECTOR',I3,' PIN =',8A1,	PAL14320
1	1 /,' EXPECT = OUTPUT ENABLE ACTUAL = 2')	PAL14330
	IF (IMESS.EQ.44) WRITE (PMS,44) NVECT, (ISYM1(J,I),J=1,8), IVECT(I)	PAL14340
44	FORMAT(/,' FUNCTION TABLE ERROR IN VECTOR',I3,' PIN =',8A1,	PAL14350
1	1 /,' EXPECT = 2 ACTUAL = ',A1)	PAL14360
	IF((IMESS.NE.40).AND.(PMS.EQ.6)) WRITE (PMS,45) BEL	PAL14370
45	FORMAT(' ',A1)	PAL14380
	IF (IMESS.NE.40) IVECT(I)=ERR	PAL14390
	IF (IMESS.NE.40) NERR=NERR+1	PAL14400
50	CONTINUE	PAL14410
C	CHANGE THE ORDER OF VECTORS FROM THE ORDER OF APPEARANCE IN THE	PAL14420
C	FUNCTION TABLE TO THAT OF THE PIN LIST AND TWEAK FOR OUTPUT	PAL14430
	DO 65 I=1,24	PAL14440
	DO 55 J=1,IMAX	PAL14450
	IF(IPIN(J).NE.1) GO TO 55	PAL14460
	IF(IVECT(J).EQ.L.OR.IVECT(J).EQ.H) GO TO 51	PAL14470
	ISTATE(I)=IVECT(J)	PAL14480
	GO TO 65	PAL14490
51	LSAME=((LPHASE(I)).AND.(LPHAS1(J)).OR.	PAL14500
1	(.NOT.LPHASE(I)).AND.(.NOT.LPHAS1(J)))	PAL14510
	IF((IYPE.EQ.5.AND.(I.EQ.18.OR.I.EQ.19)) LOUT(J)=.TRUE.	PAL14520
	IF((.NOT.LOUT(J)).AND.(LSAME).AND.	PAL14530
1	IVECT(J).EQ.L) ISTATE(I)=NO	PAL14540
1	IF((.NOT.LOUT(J)).AND.(LSAME).AND.	PAL14550
1	IVECT(J).EQ.H) ISTATE(I)=H	PAL14560
1	IF((.NOT.LOUT(J)).AND.(.NOT.LSAME).AND.	PAL14570
1	IVECT(J).EQ.L) ISTATE(I)=H	PAL14580
1	IF((.NOT.LOUT(J)).AND.(.NOT.LSAME).AND.	PAL14590
1	IVECT(J).EQ.H) ISTATE(I)=NO	PAL14600
1	IF((LOUT(J)).AND.(LSAME).AND.	PAL14610
1	IVECT(J).EQ.L.AND.(LENABL(J)) ISTATE(I)=L	PAL14620
1	IF((LOUT(J)).AND.(LSAME).AND.	PAL14630
1	IVECT(J).EQ.H.AND.(LENABL(J)) ISTATE(I)=H	PAL14640
1	IF((LOUT(J)).AND.(.NOT.LSAME).AND.	PAL14650
1	IVECT(J).EQ.L.AND.(LENABL(J)) ISTATE(I)=H	PAL14660
1	IF((LOUT(J)).AND.(.NOT.LSAME).AND.	PAL14670
1	IVECT(J).EQ.H.AND.(LENABL(J)) ISTATE(I)=L	PAL14680
	IF(IVECT(J).EQ.ERR) ISTATE(I)=ERR	PAL14690
	GO TO 65	PAL14700
55	CONTINUE	PAL14710
C	SAVE PRESENT VECTORS FOR FEED BACK USED WITH NEXT SET OF VECTORS	PAL14720
C	IF CLOCK PULSE AND NOT Z (HI-Z IS ASYNCHRONOUS)	PAL14730
65	IF((LCLOCK).AND.IVECT(J).NE.Z) IVECTP(J)=IVECT(J)	PAL14740
C	ASSIGN X TO GROUND PIN AND 1 TO VCC PIN	PAL14750
	ISTATE(12)=X	PAL14760
	ISTATE(24)=H	PAL14770
C	PRINT TEST VECTORS	PAL14780
	IF((.NOT.LSA11).AND.(.NOT.LSA01))WRITE(POF,60)	PAL14790
1	1 NVECT, (ISTATE(I),I=1,24)	PAL14800
60	FORMAT(' ',I3,' ',24A1)	PAL14810
	GO TO 90	PAL14820
C	TERMINATE SIMULATION	PAL14830
C		PAL14840
95	IF((.NOT.LERR).AND.(LSA11)) WRITE(POF,150) IPCTR4,IEQN1	PAL14850

150	FORMAT(' ', ' PRODUCT: ', I3, ' OF ', 'EQUATION', I3, ' 1 UNTESTED(SA1) FAULT')	PAL14860
	IF((.NOT.LERR).AND.(LSA01)) WRITE(POF,155) IPCTR4, IEQN1	PAL14870
155	FORMAT(' ', ' PRODUCT: ', I3, ' OF ', 'EQUATION', I3, ' 1 UNTESTED(SA0) FAULT')	PAL14880
	IF((.NOT.LERR).AND.(.NOT.LSA11).AND.(.NOT.LSA01)) WRITE(POF,67)	PAL14890
	IPCTR=IPCIR/(NVECT-1)	PAL14900
	IF((.NOT.LERR).AND.(.NOT.LSA11).AND.(.NOT.LSA01))	PAL14910
	WRITE(POF,68) MERR	PAL14920
67	FORMAT('/', ' PASS SIMULATION')	PAL14930
	IPCTR=IPCIR/(NVECT-1)	PAL14940
	IF((.NOT.LERR).AND.(.NOT.LSA11).AND.(.NOT.LSA01))	PAL14950
	WRITE(POF,68) MERR	PAL14960
68	FORMAT('/', ' NUMBER OF FUNCTION TABLE ERRORS = ', I3)	PAL14970
	RETURN	PAL14980
C	PRINT AN ERROR MESSAGE FOR AN UNDEFINED PIN NAME	PAL14990
100	ILERR=ILL+4	PAL15000
	WRITE(PMS,101) (IBJF(I,1),I=1,8), ILERR, (IPAGE(I,ILL),I=1,80)	PAL15010
101	FORMAT('/', ' ERROR SYMBOL = ', 8A1, ' IN LINE NUMBER ', I3, 1 /, ' ', 80A1, /, ' THIS PIN NAME IS NOT DEFINED IN THE', 2 ' FUNCTION TABLE PIN LIST')	PAL15020
	RETURN	PAL15030
		PAL15040
		PAL15050
C		PAL15060
110	IPROD=H	PAL15070
	LSA12=.TRUE.	PAL15080
	IEQN1=IEQN	PAL15090
	IPCTR4=IPCTR3	PAL15100
	GO TO 38	PAL15110
C		PAL15120
C		PAL15130
C		PAL15140
120	IPROD=L	PAL15150
	LSA02=.TRUE.	PAL15160
	IEQN1=IEQN	PAL15170
	IPCTR4=IPCTR3	PAL15180
	GO TO 121	PAL15190
C		PAL15200
C		PAL15210
C		PAL15220
115	ISAF=ISAF+1	PAL15230
	LERR=.FALSE.	PAL15240
	RETURN	PAL15250
C		PAL15260
	END	PAL15270

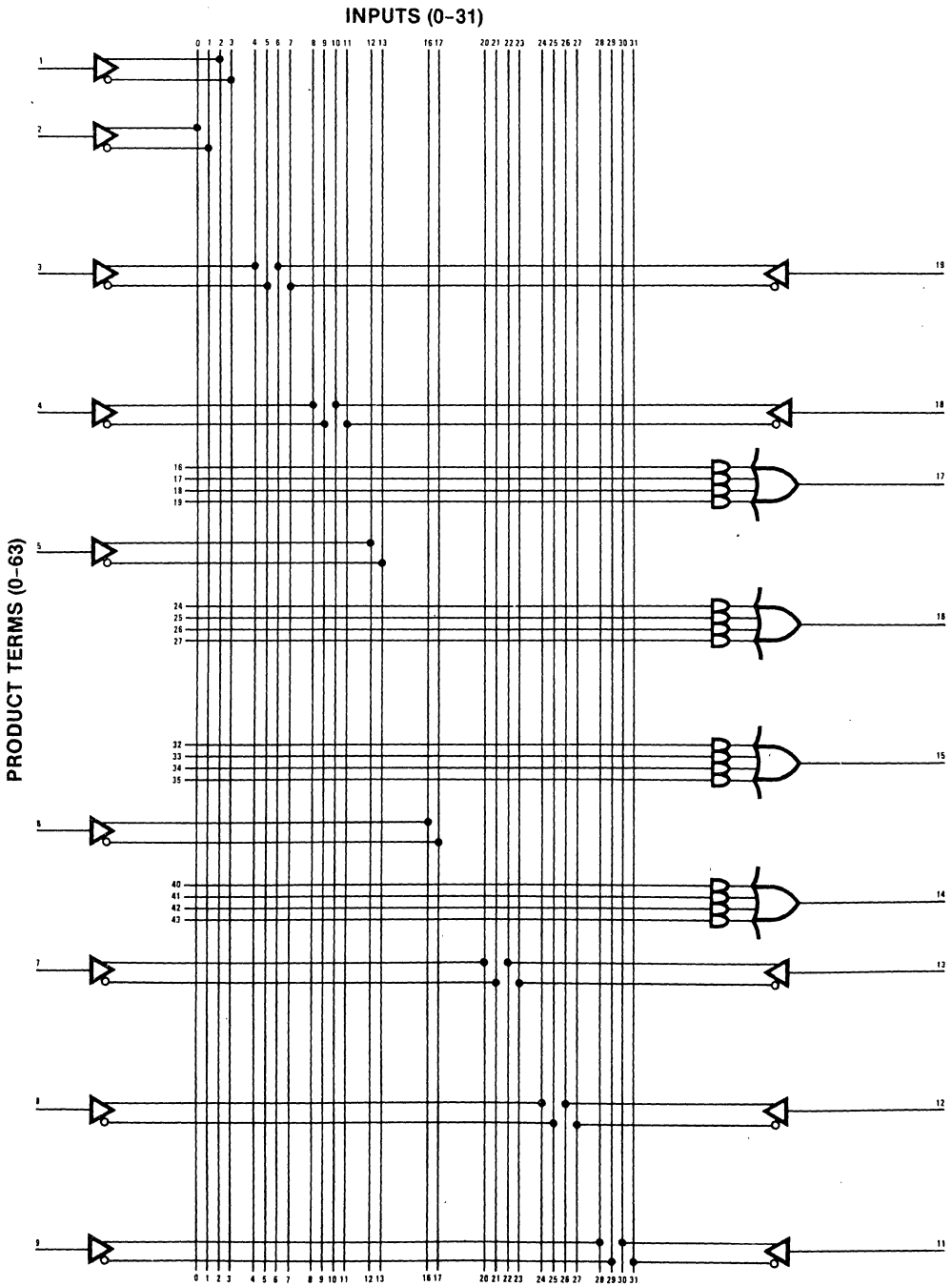
Logic Diagram PAL10H8

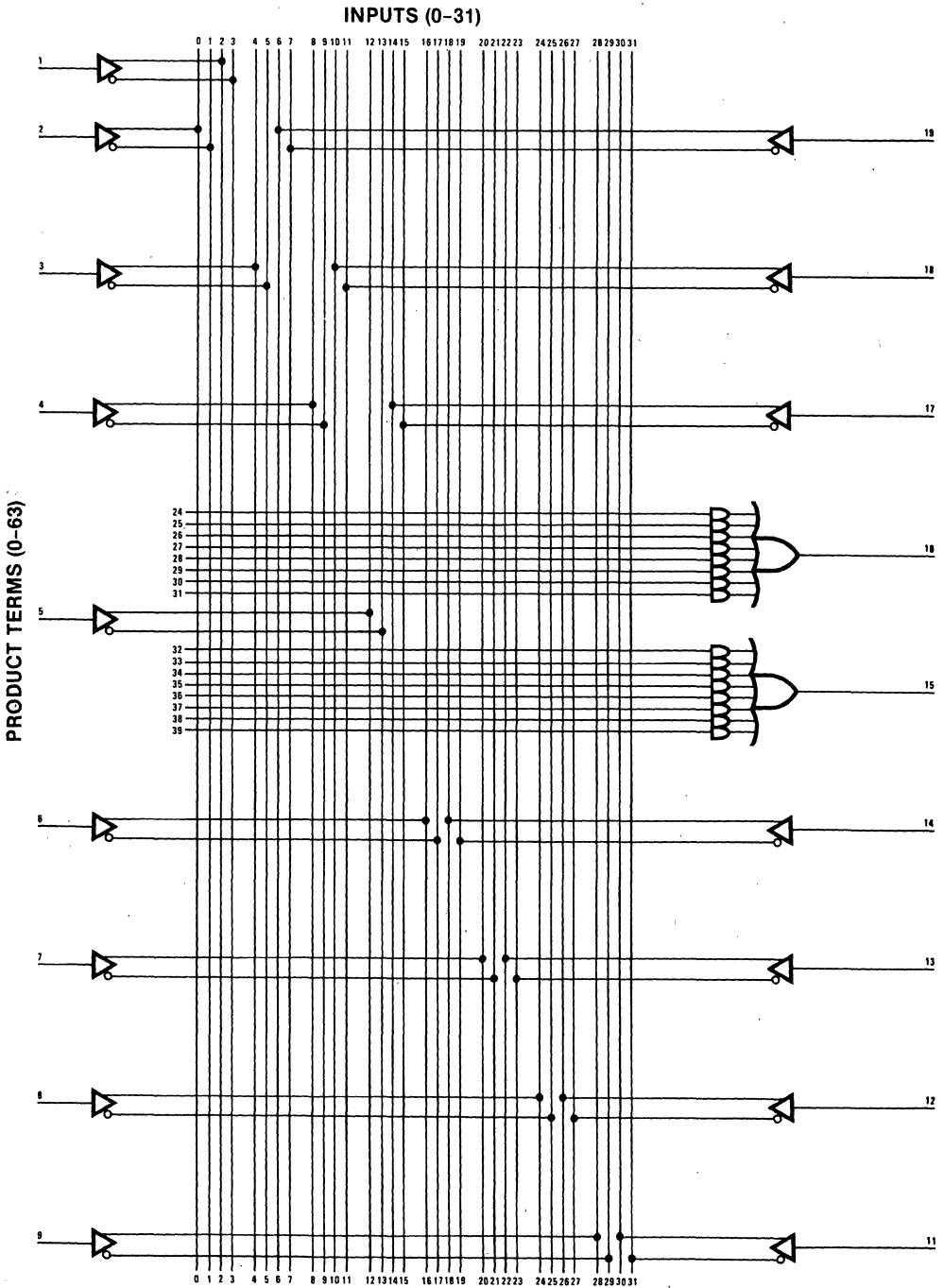




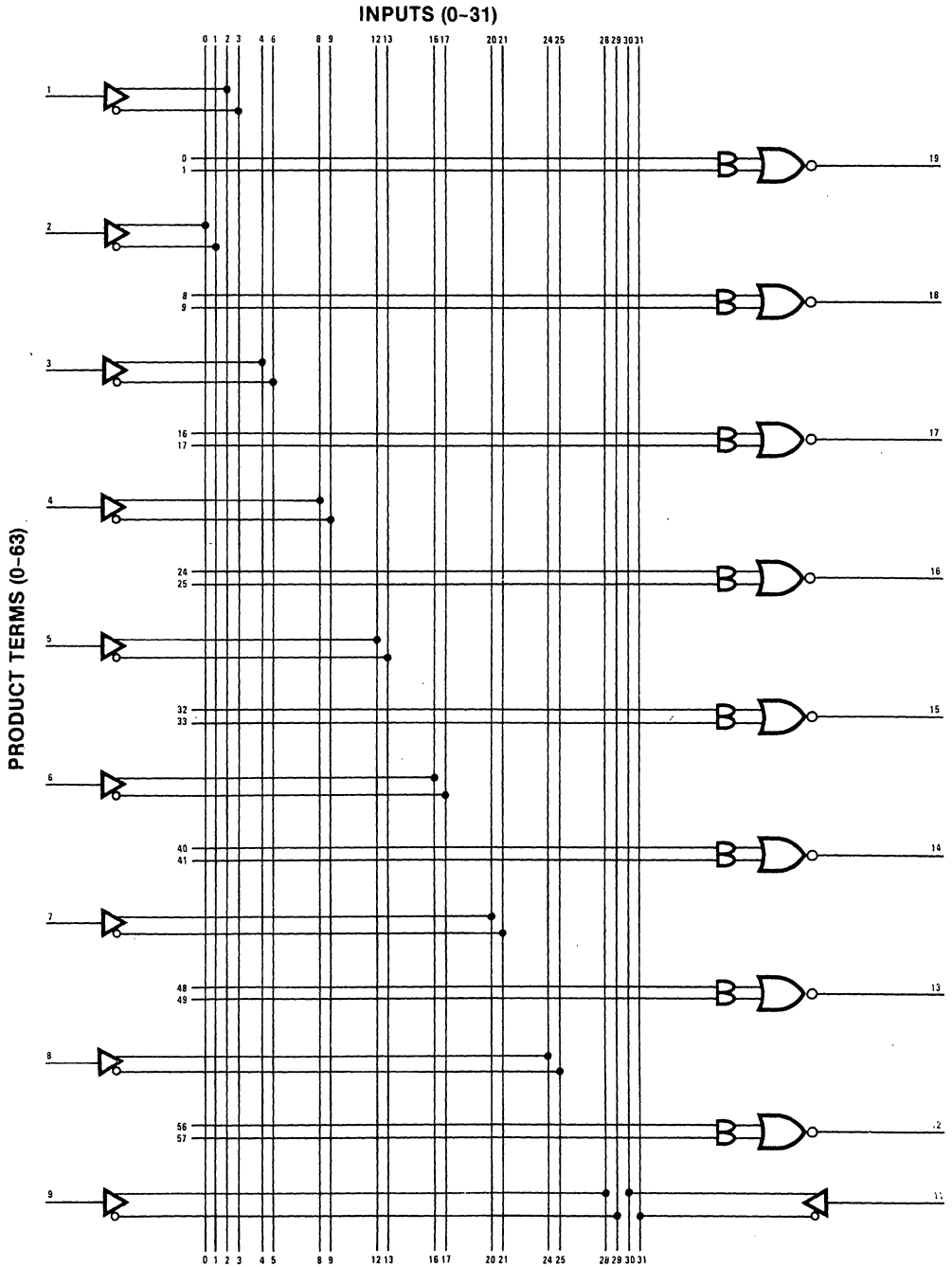
Logic Diagram PAL14H4

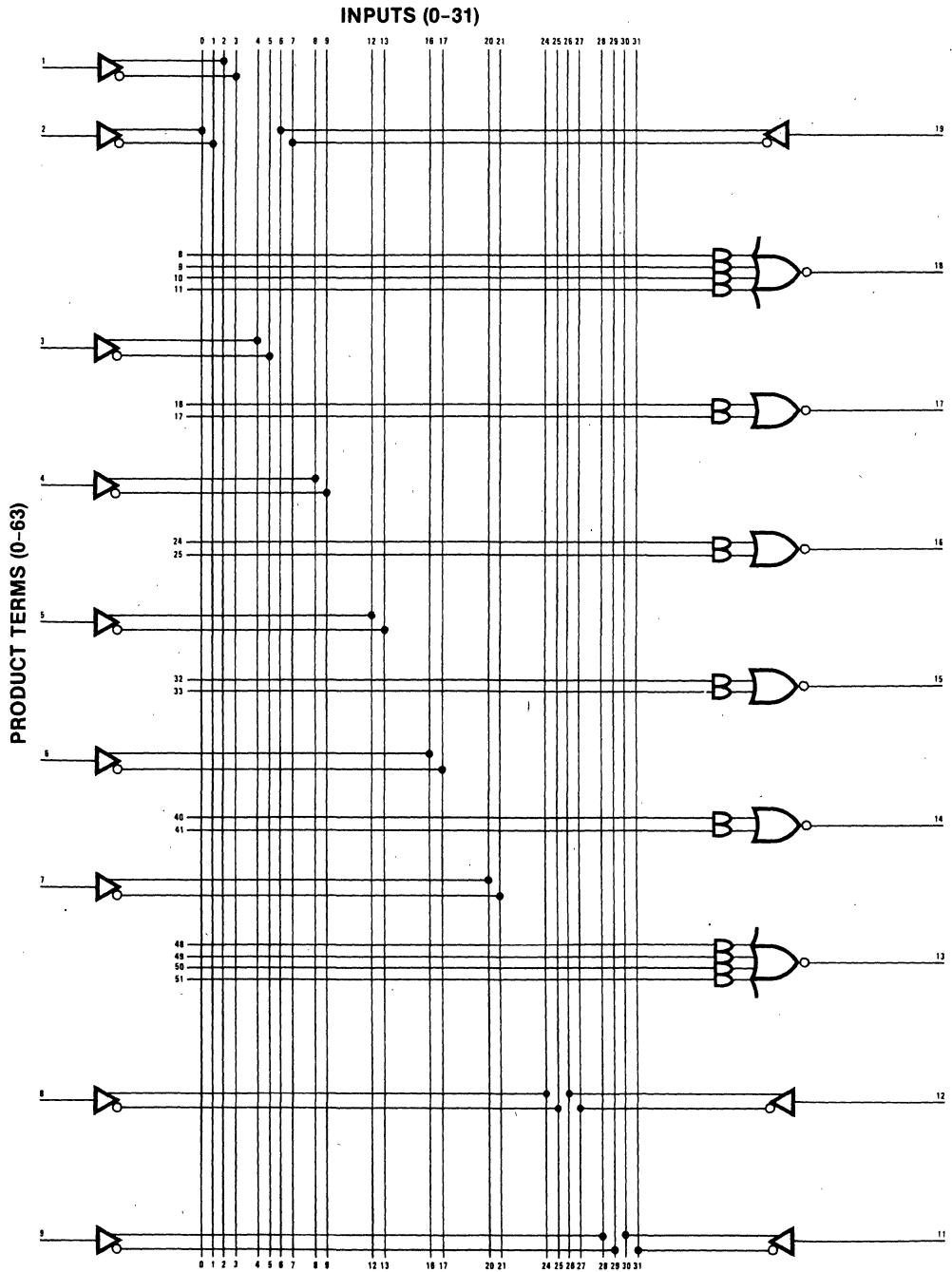
PAL Design



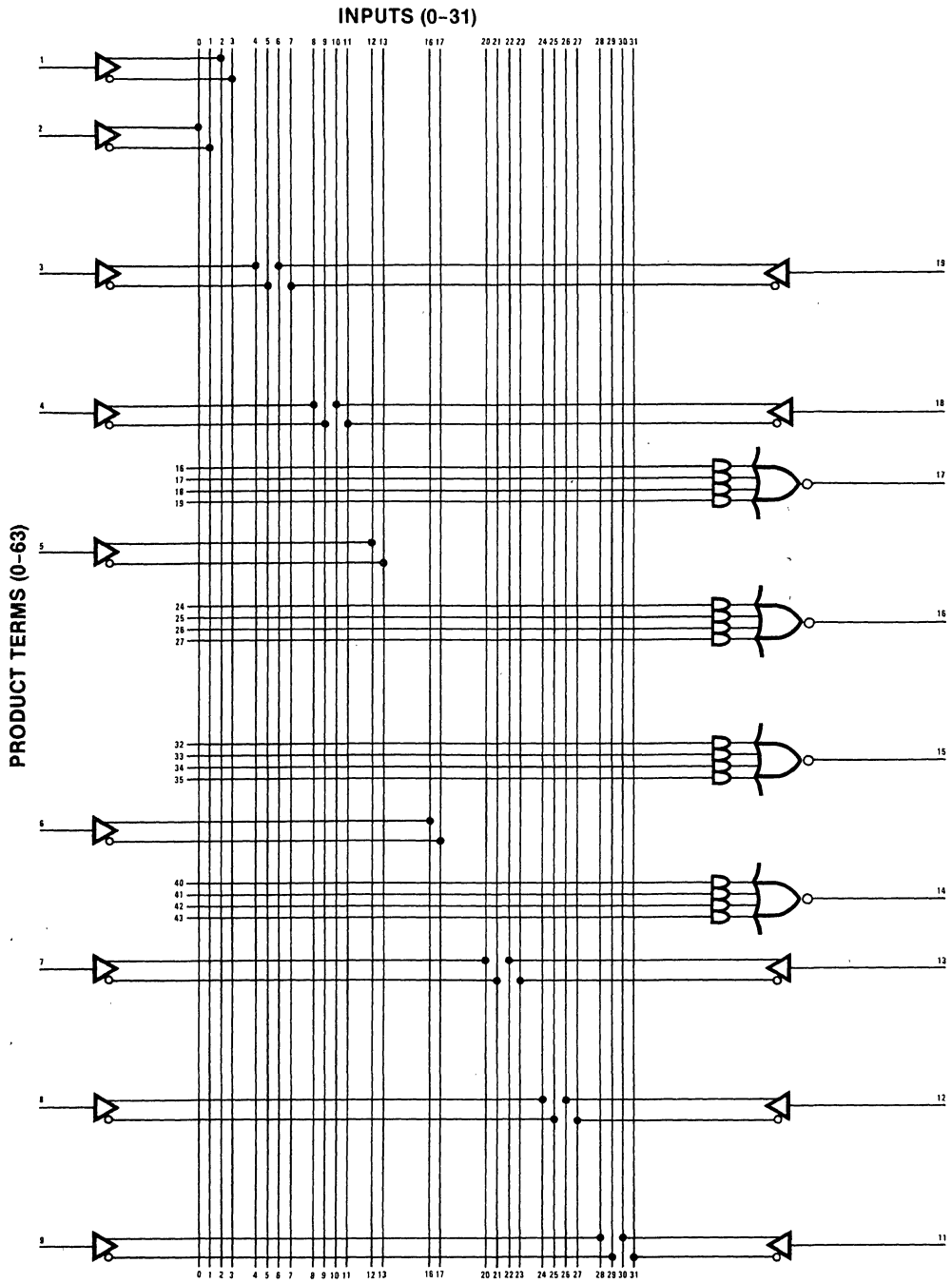


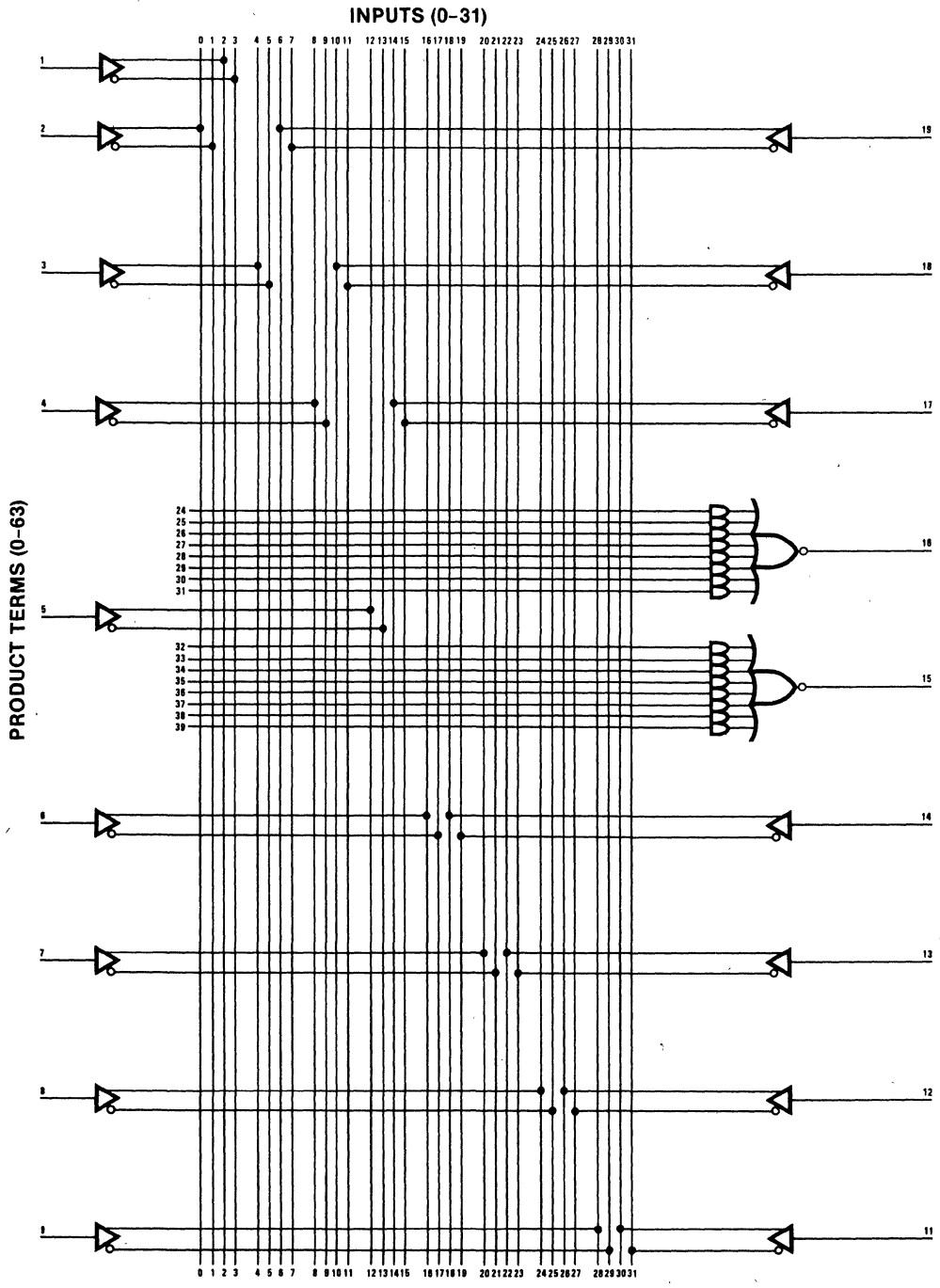
Logic Diagram PAL10L8



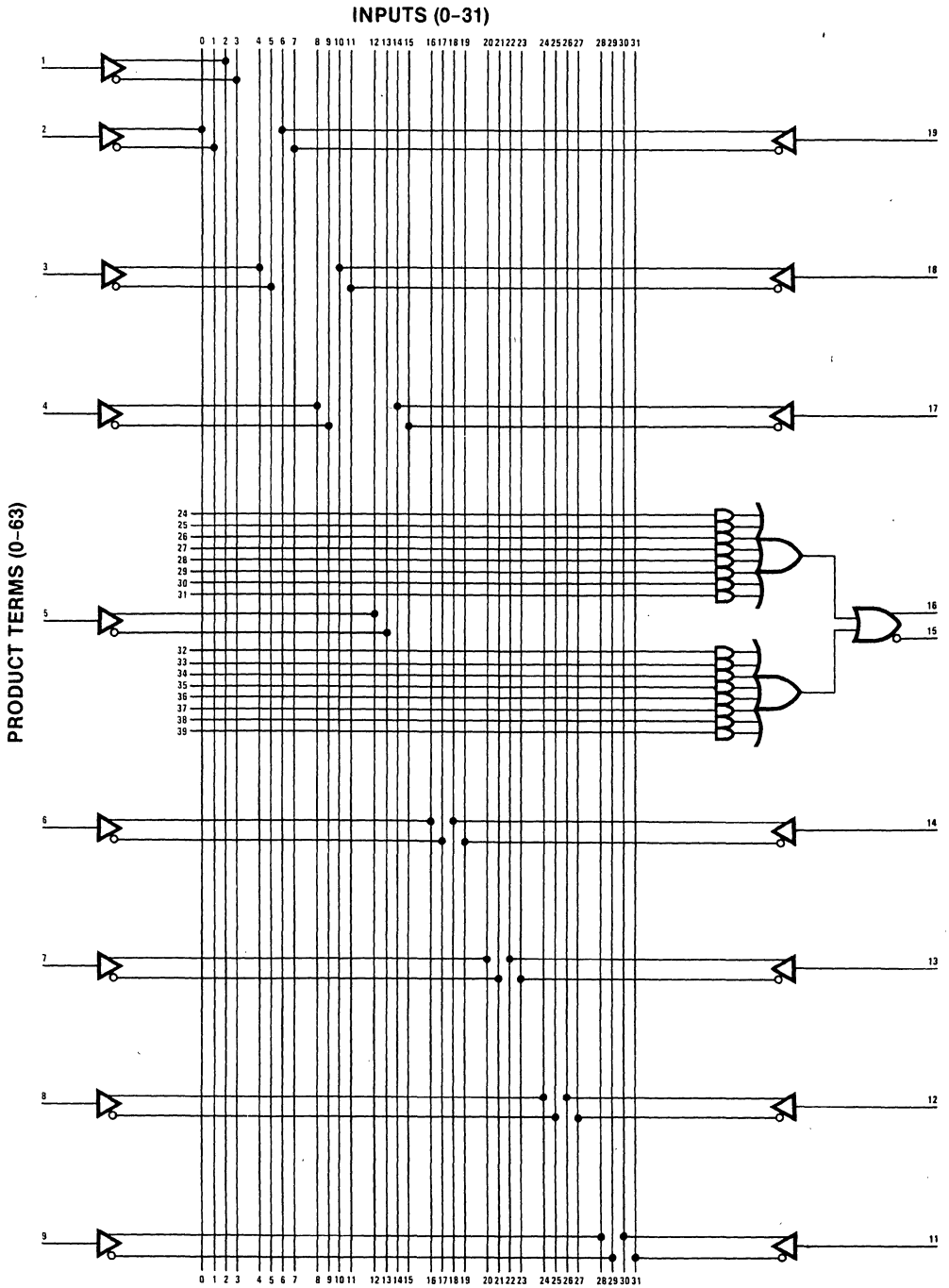


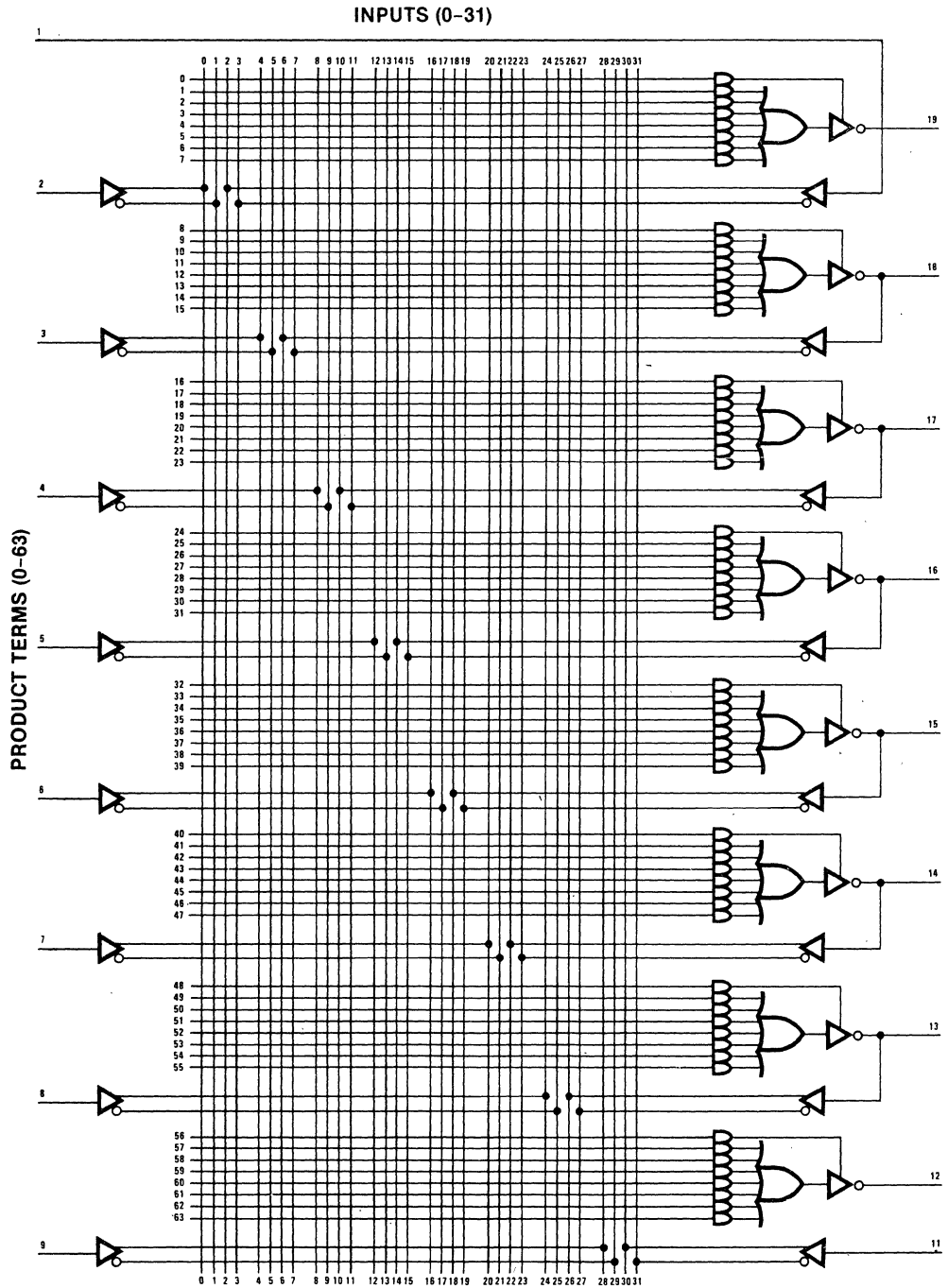
Logic Diagram PAL14L4



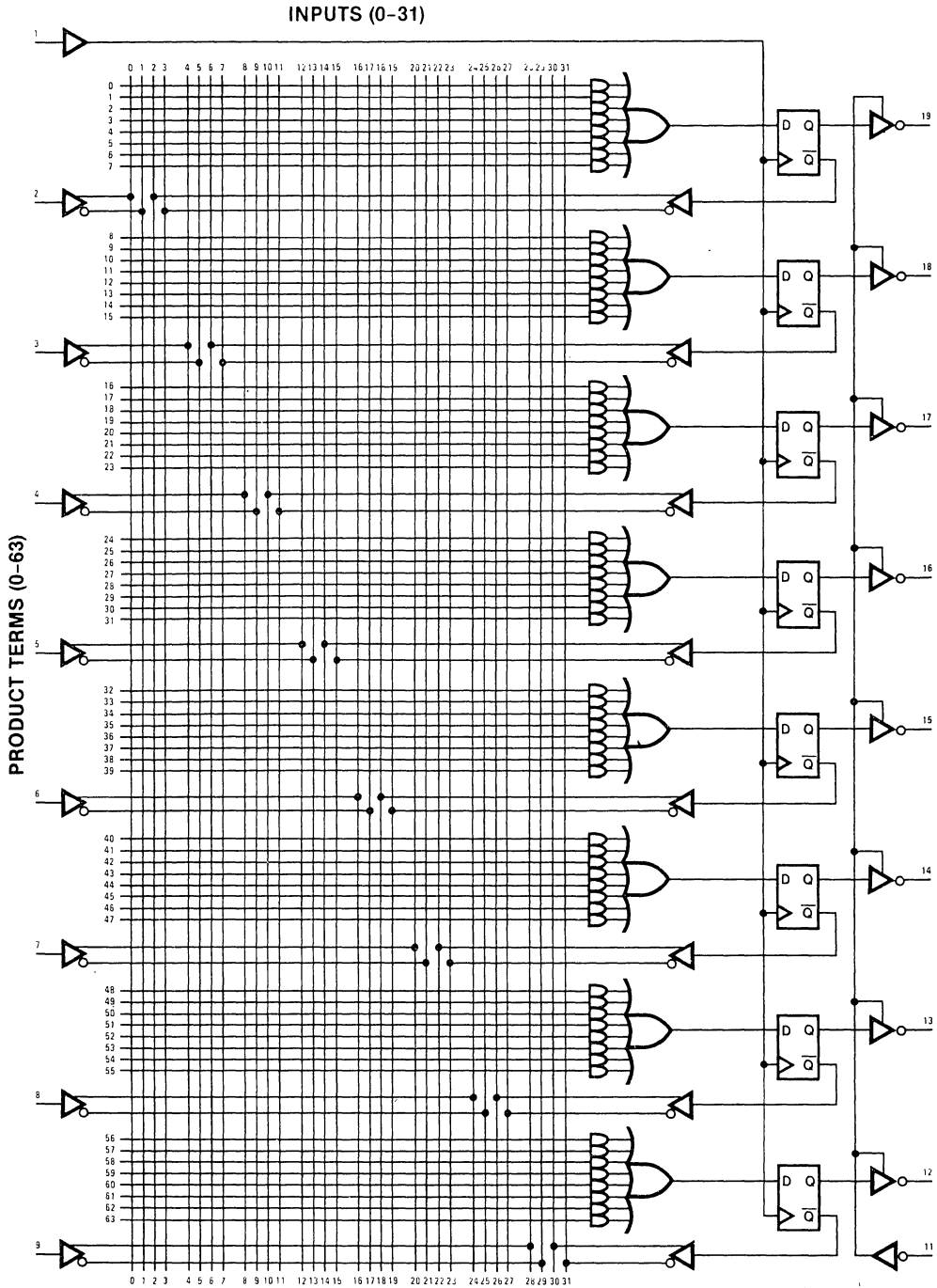


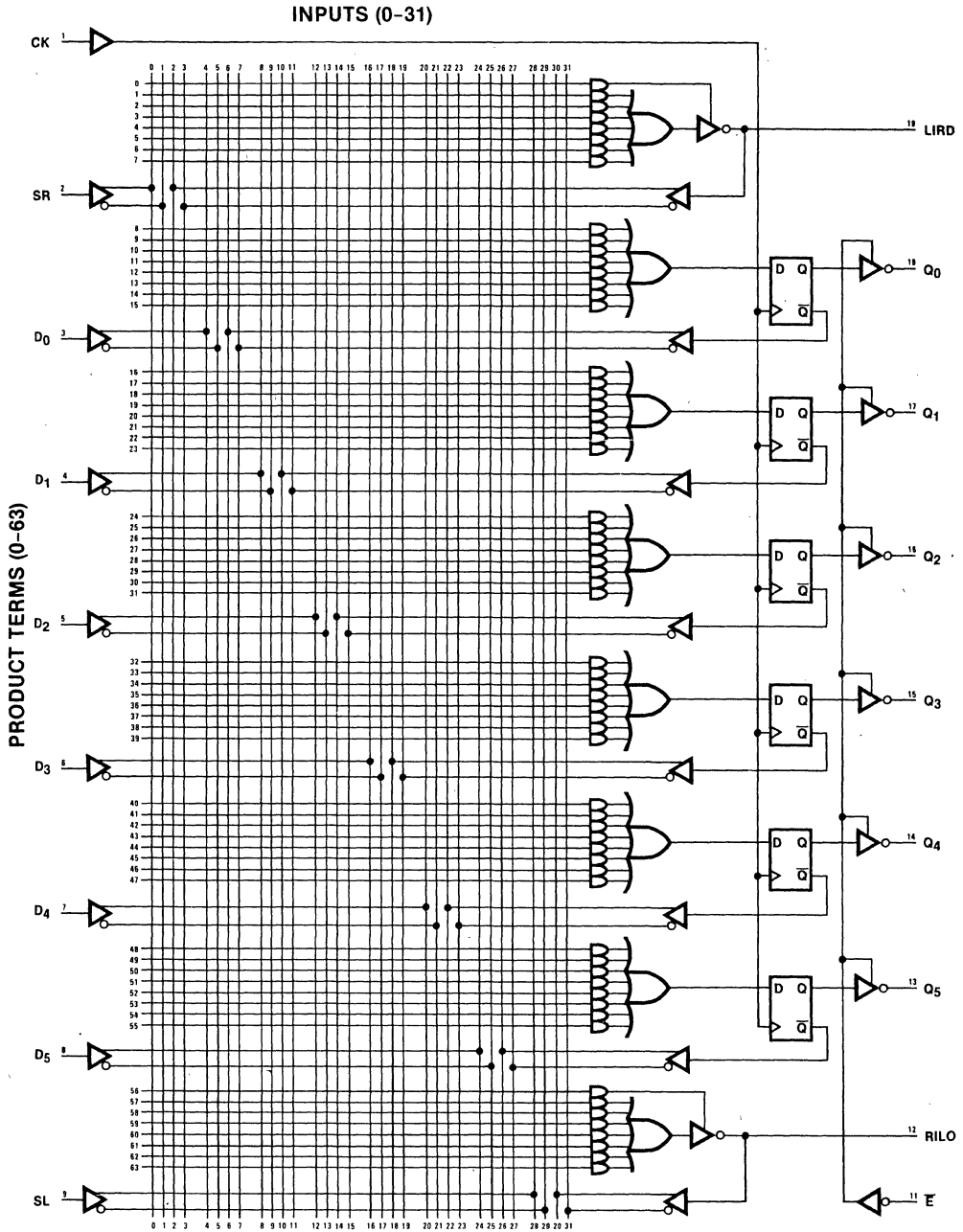
Logic Diagram PAL16C1





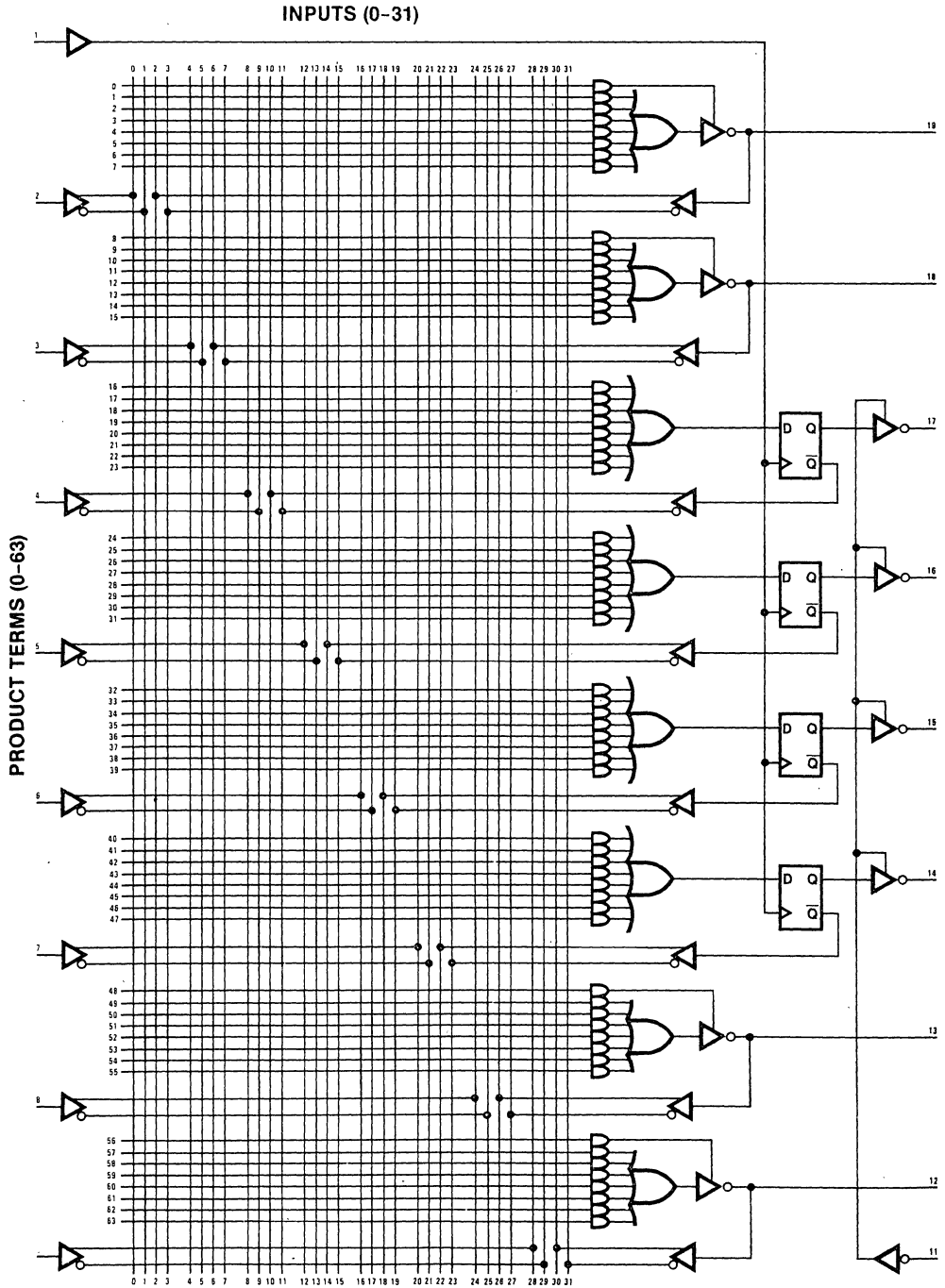
Logic Diagram PAL16R8



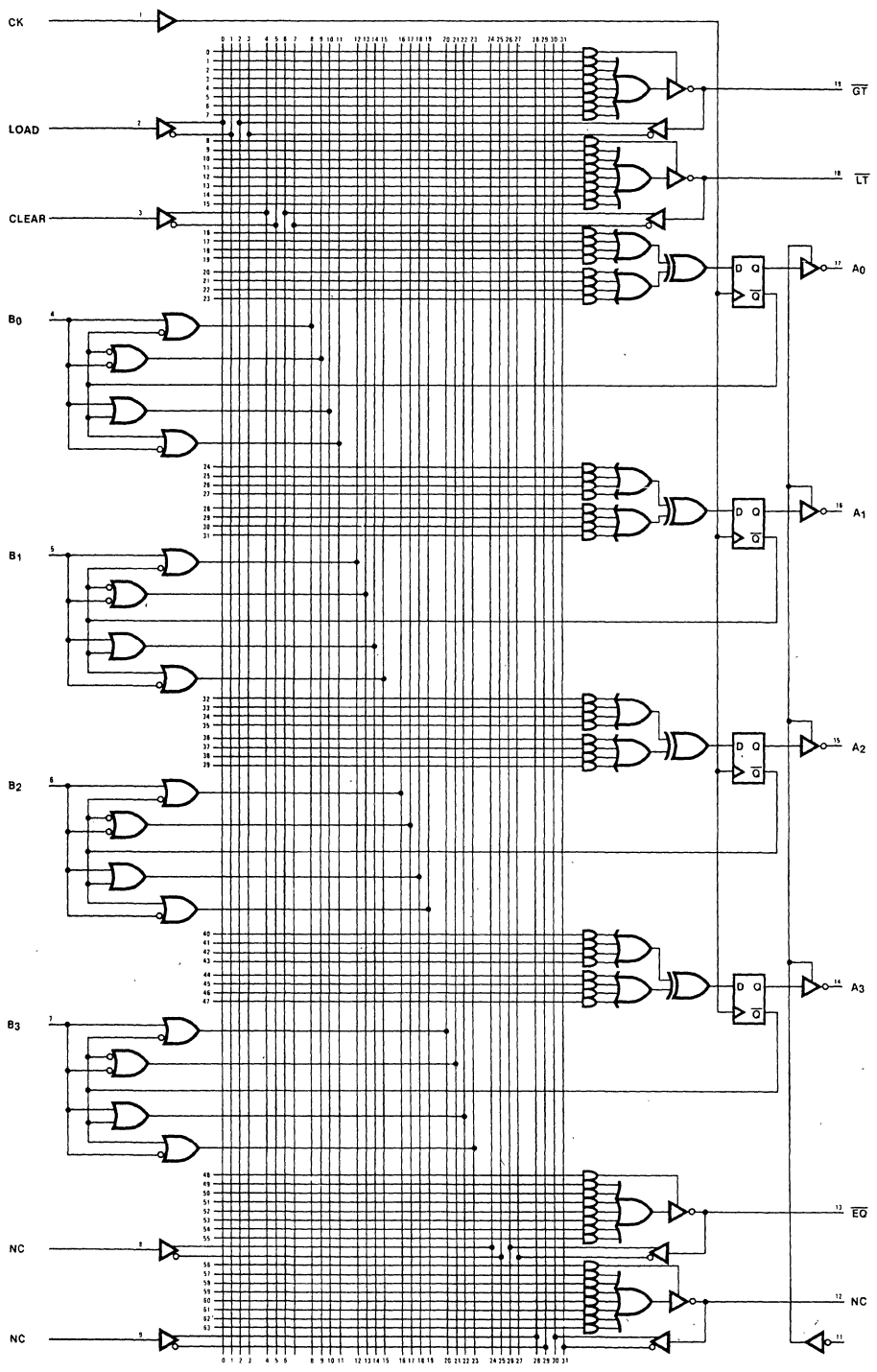


Logic Diagram PAL16R4

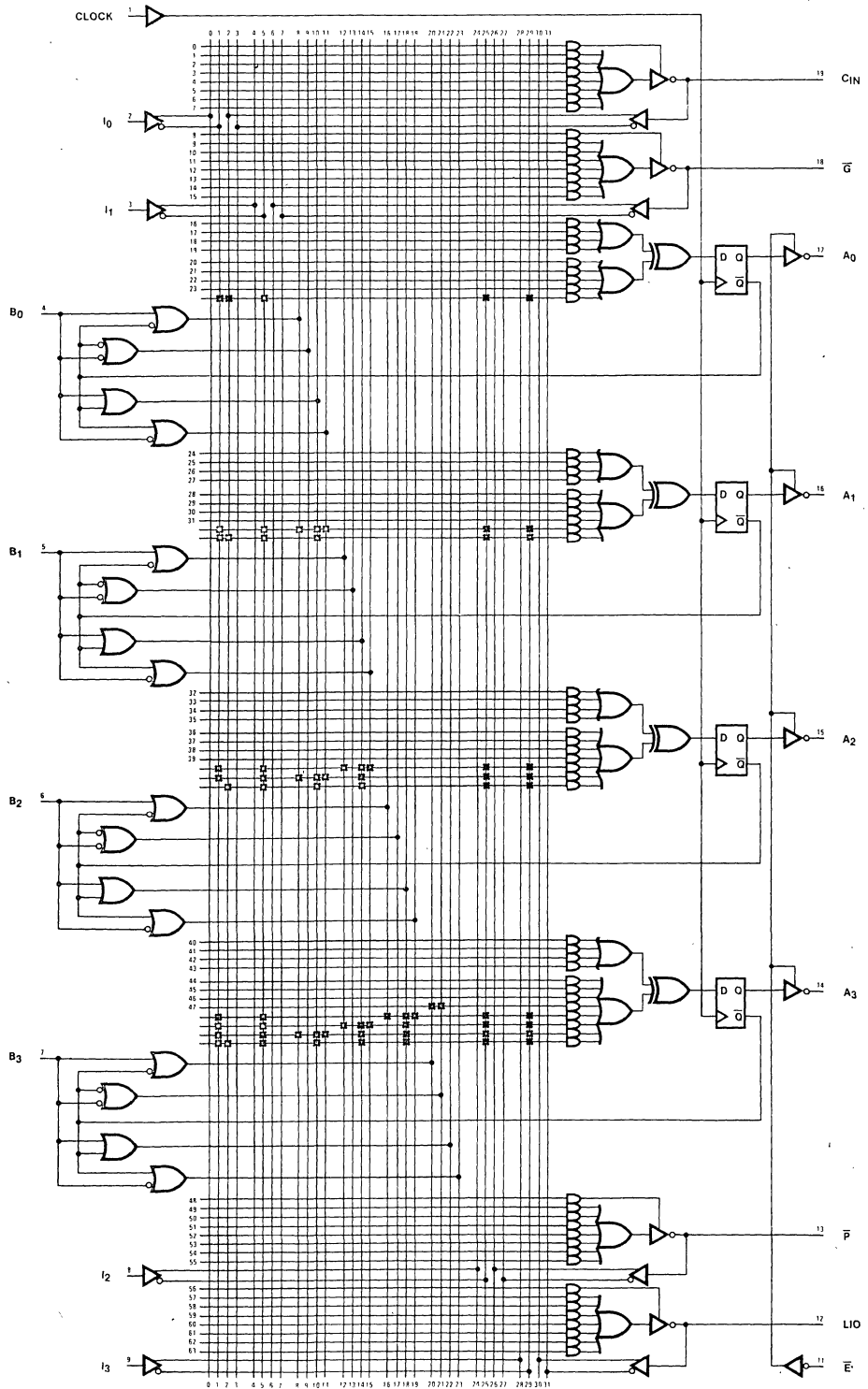
PAL Design



Logic Diagram PAL16X4



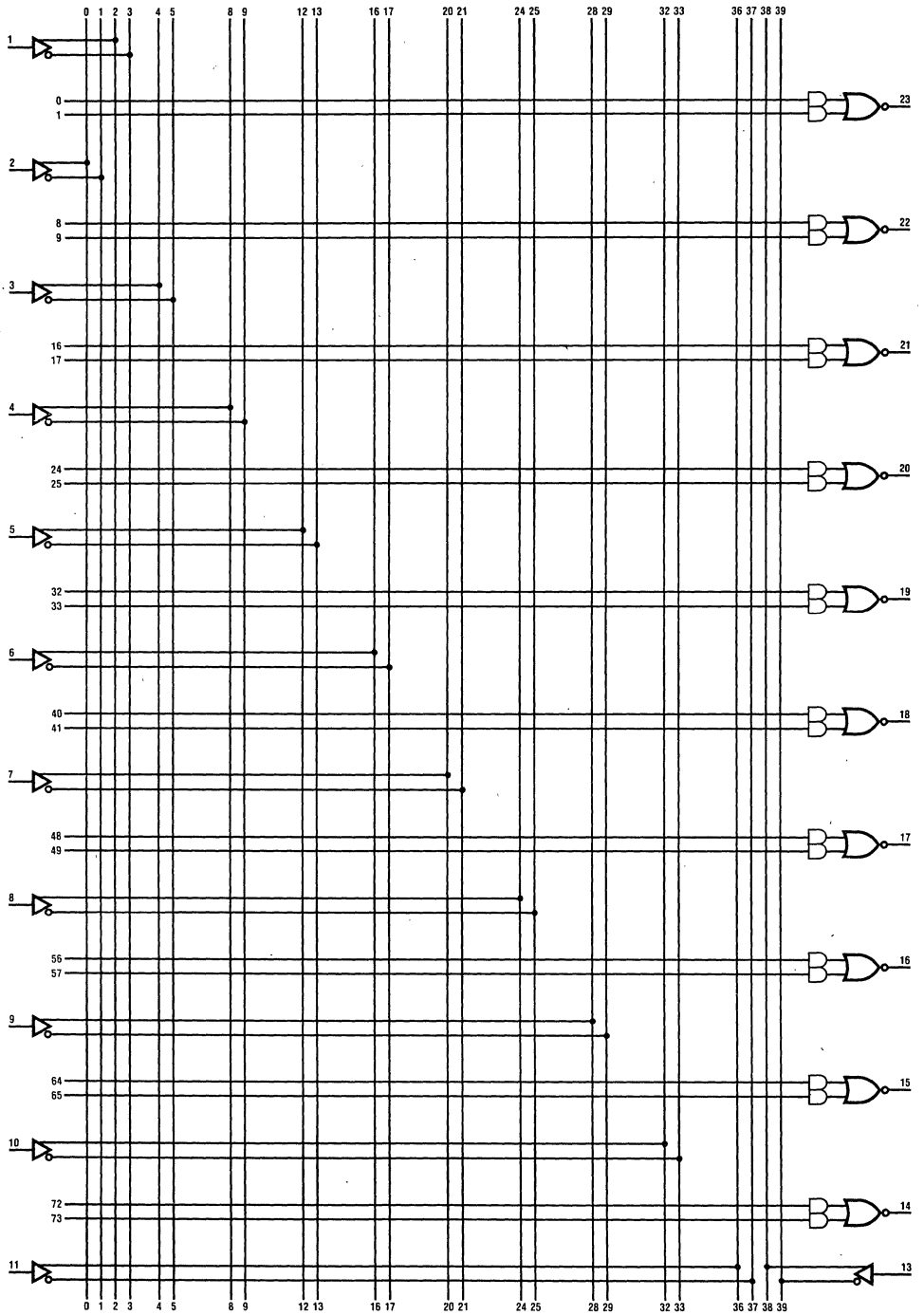
Logic Diagram PAL16A4



Logic Diagram

DMPAL12L10

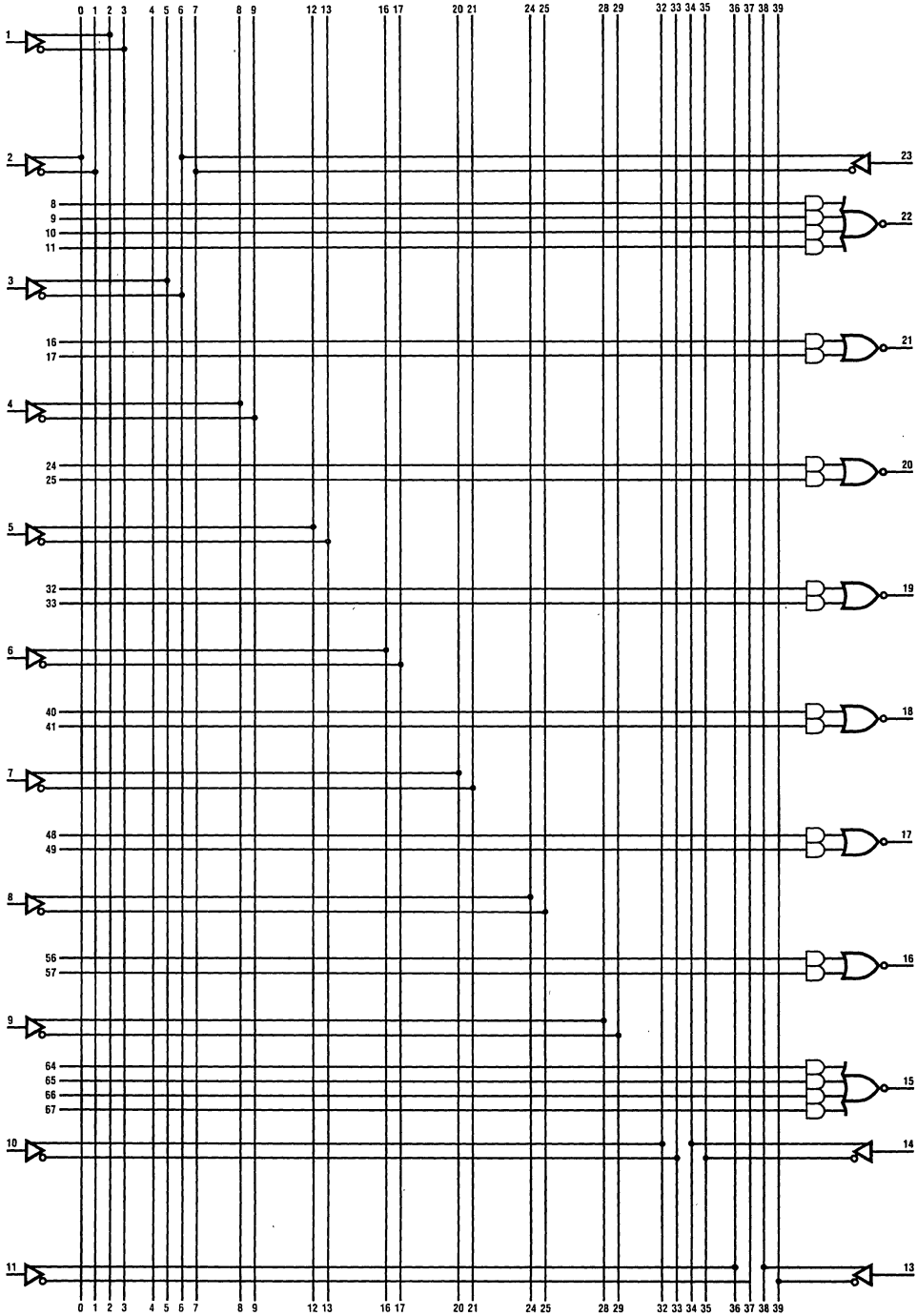
Inputs (0-39)



Logic Diagram

DMPAL14L8

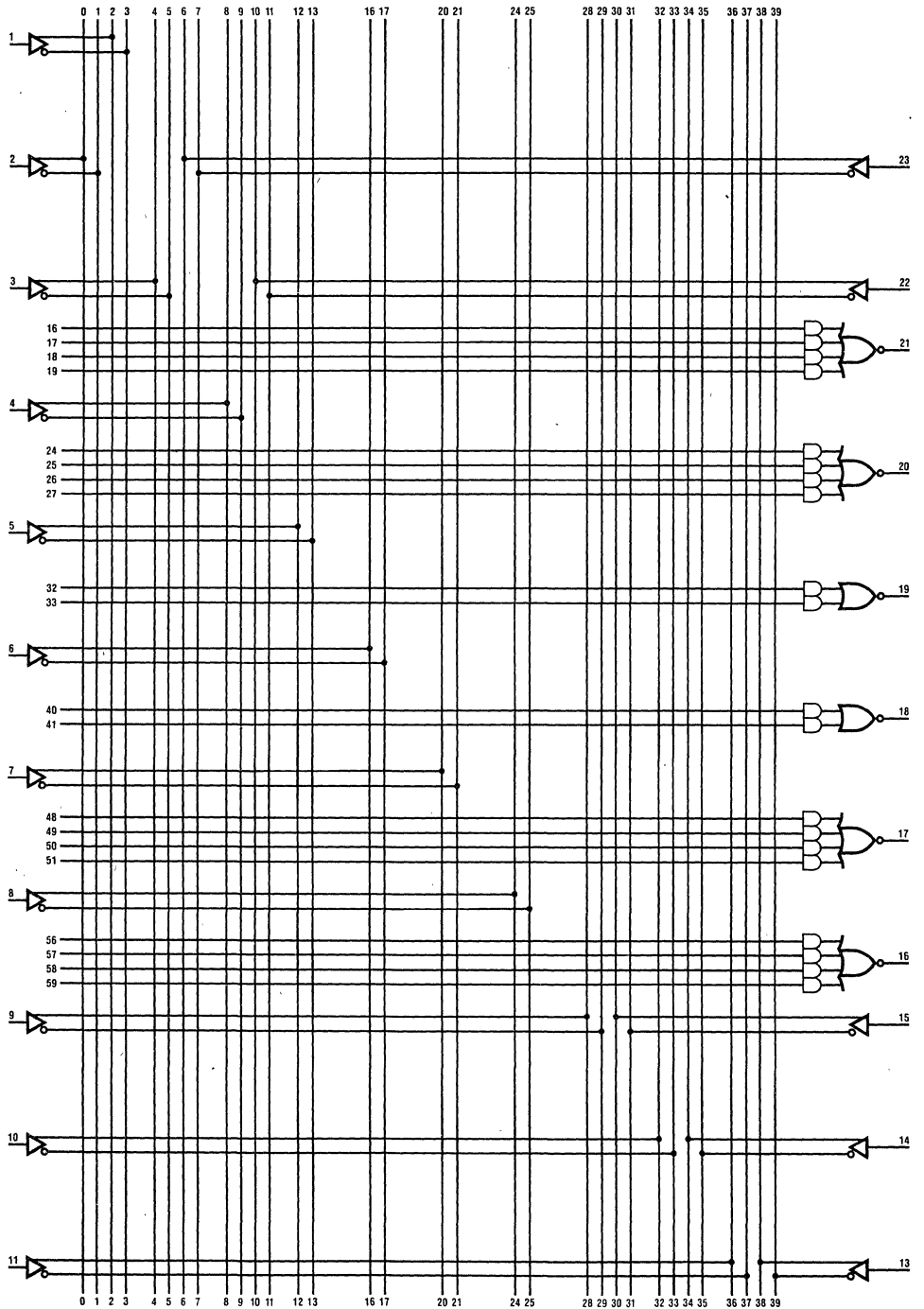
Inputs (0-39)



Logic Diagram

DMPAL16L6

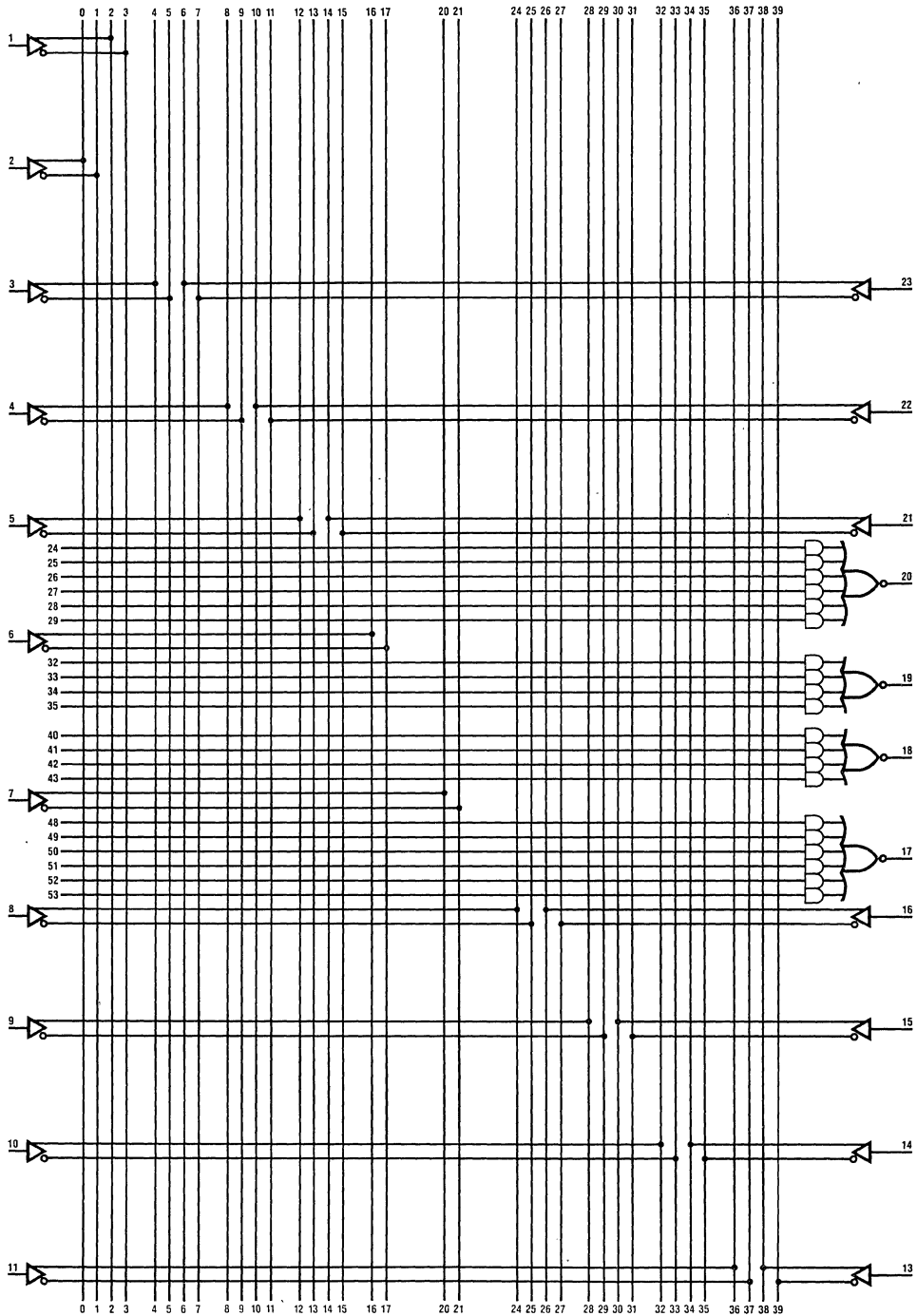
Inputs (0-39)



Logic Diagram

DMPAL18L4

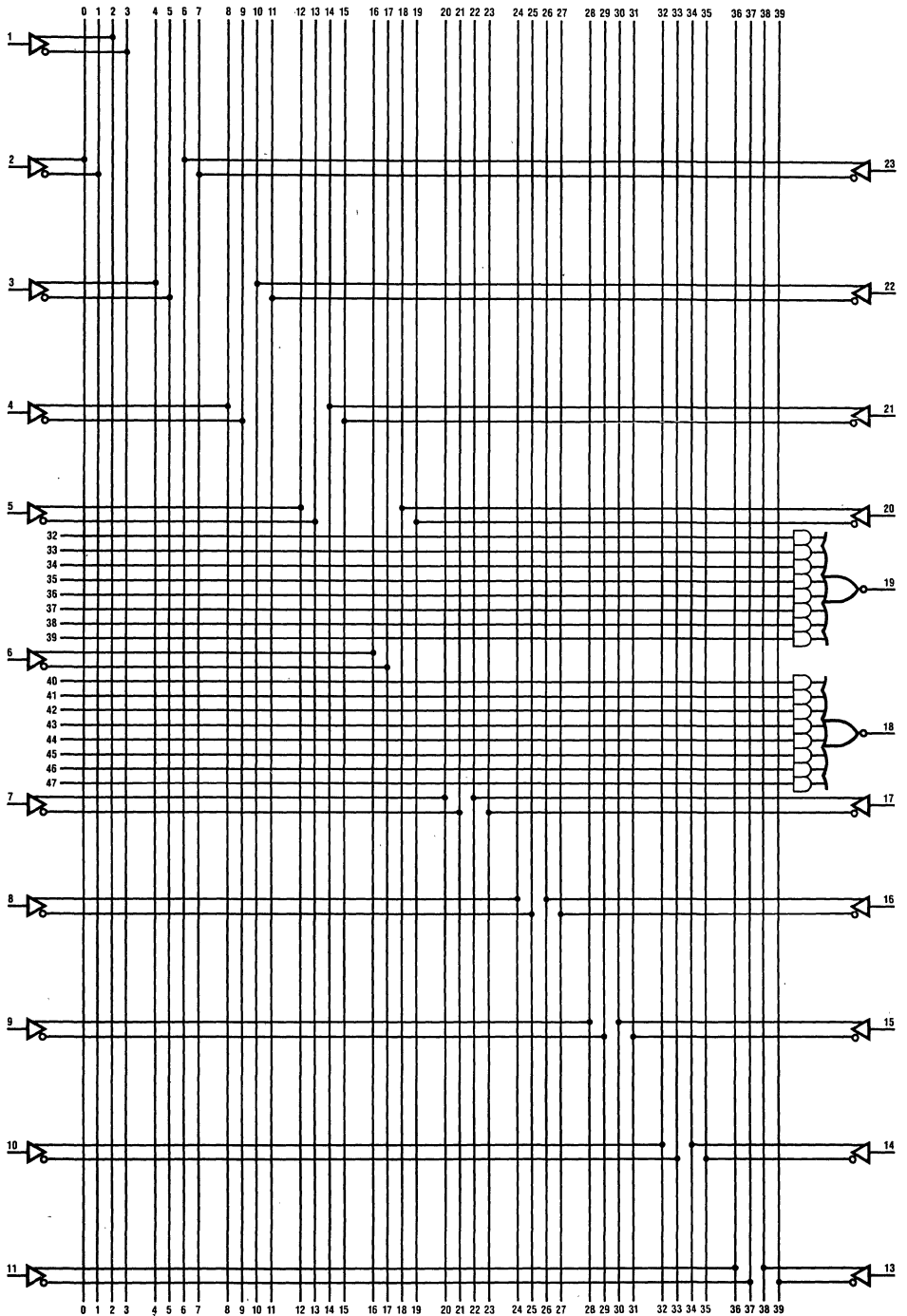
Inputs (0-39)



Logic Diagram

DMPAL20L2

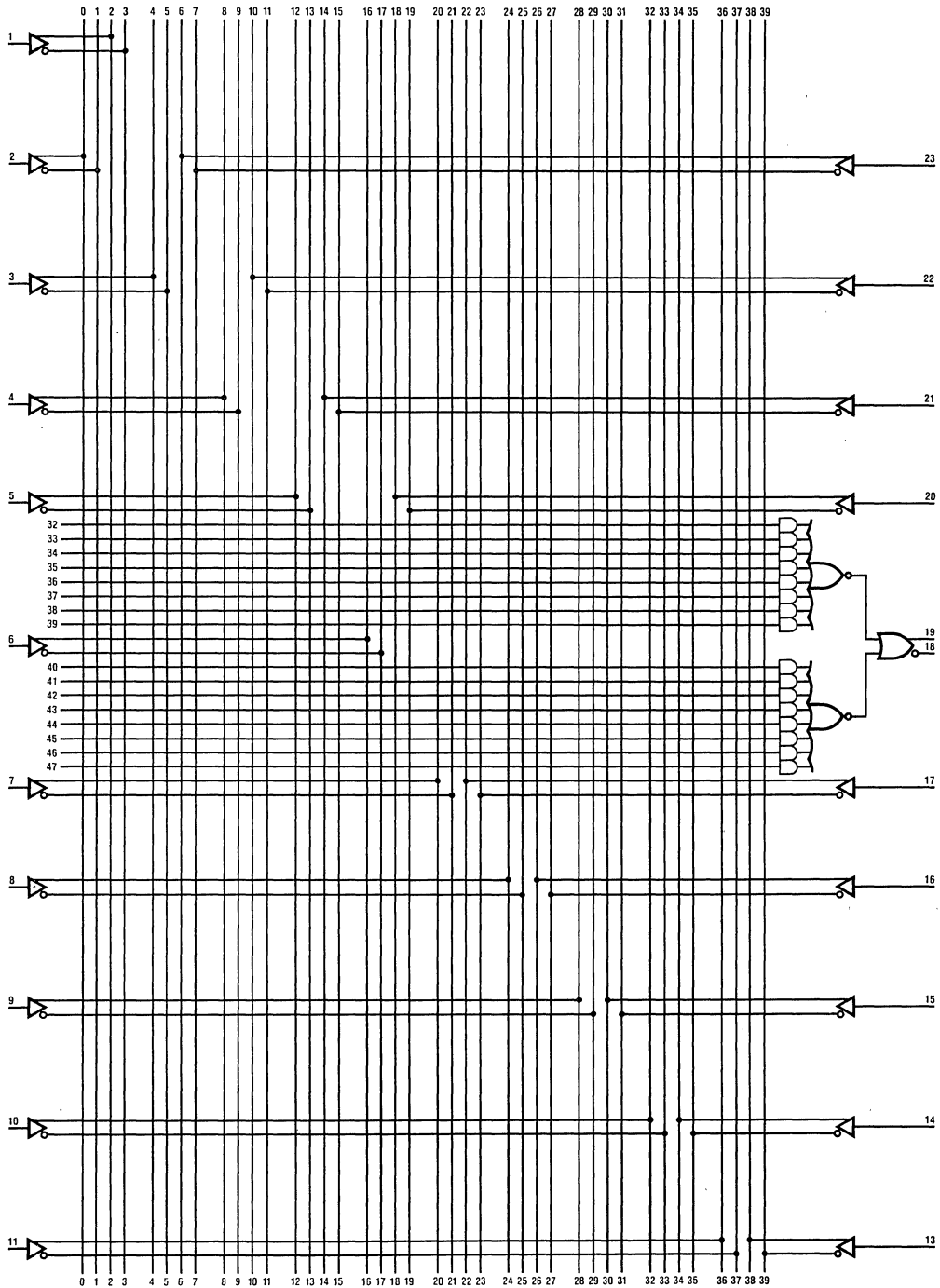
Inputs (0-39)



Logic Diagram

DMPAL20C1

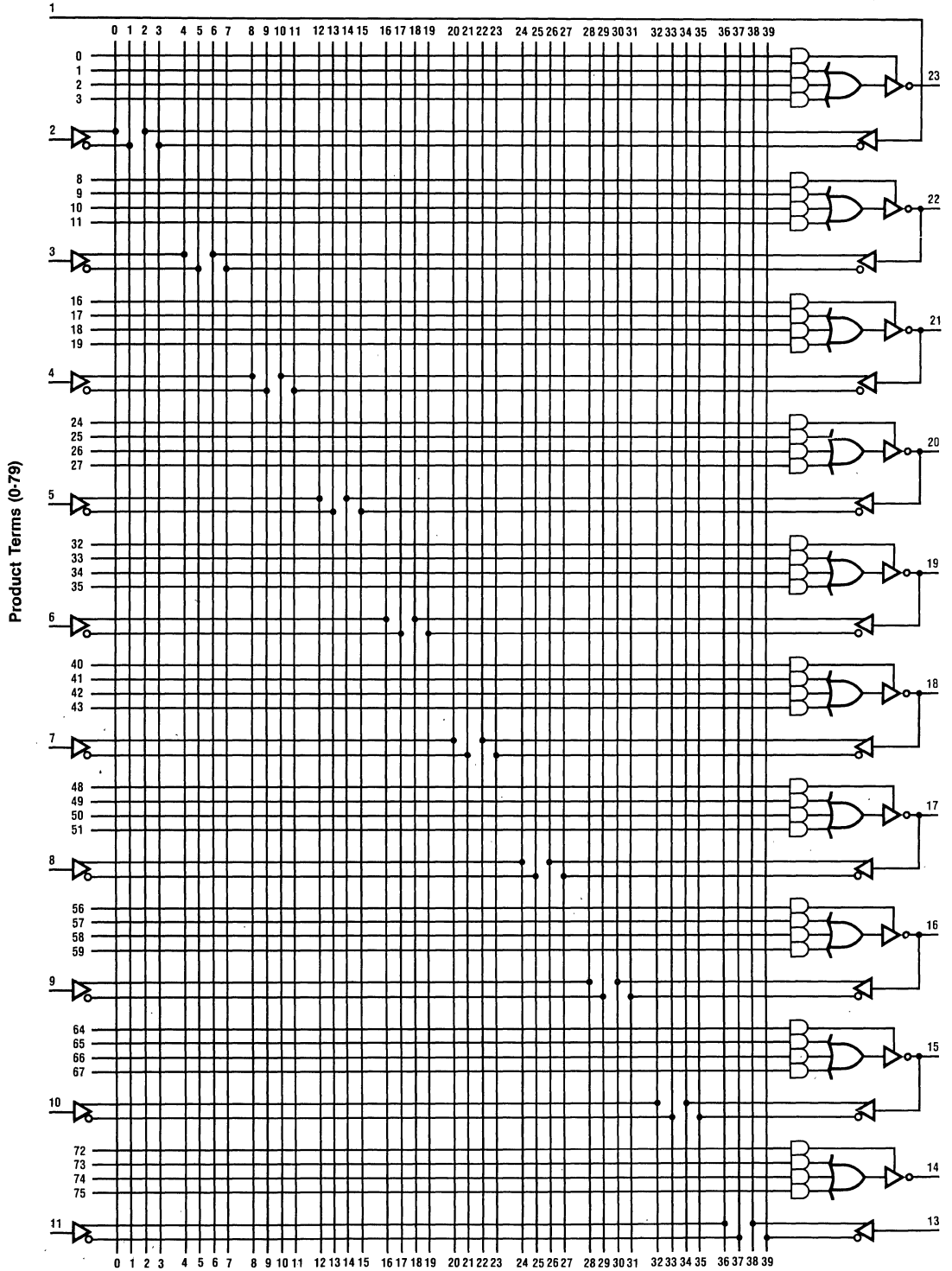
Inputs (0-39)



Logic Diagram

DMPAL20L10

Inputs (0-39)

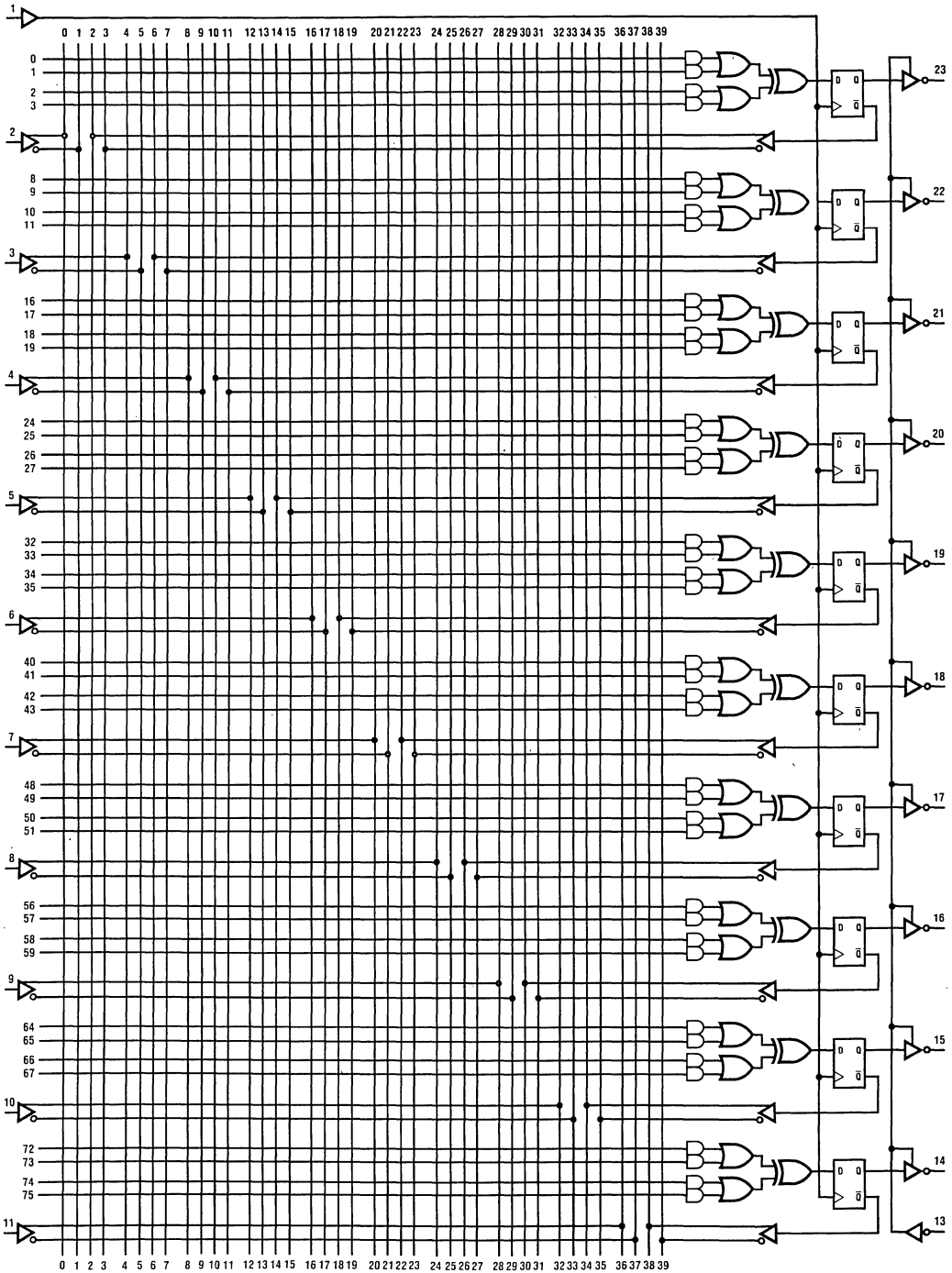


Logic Diagram

DMPAL20X10

Inputs (0-39)

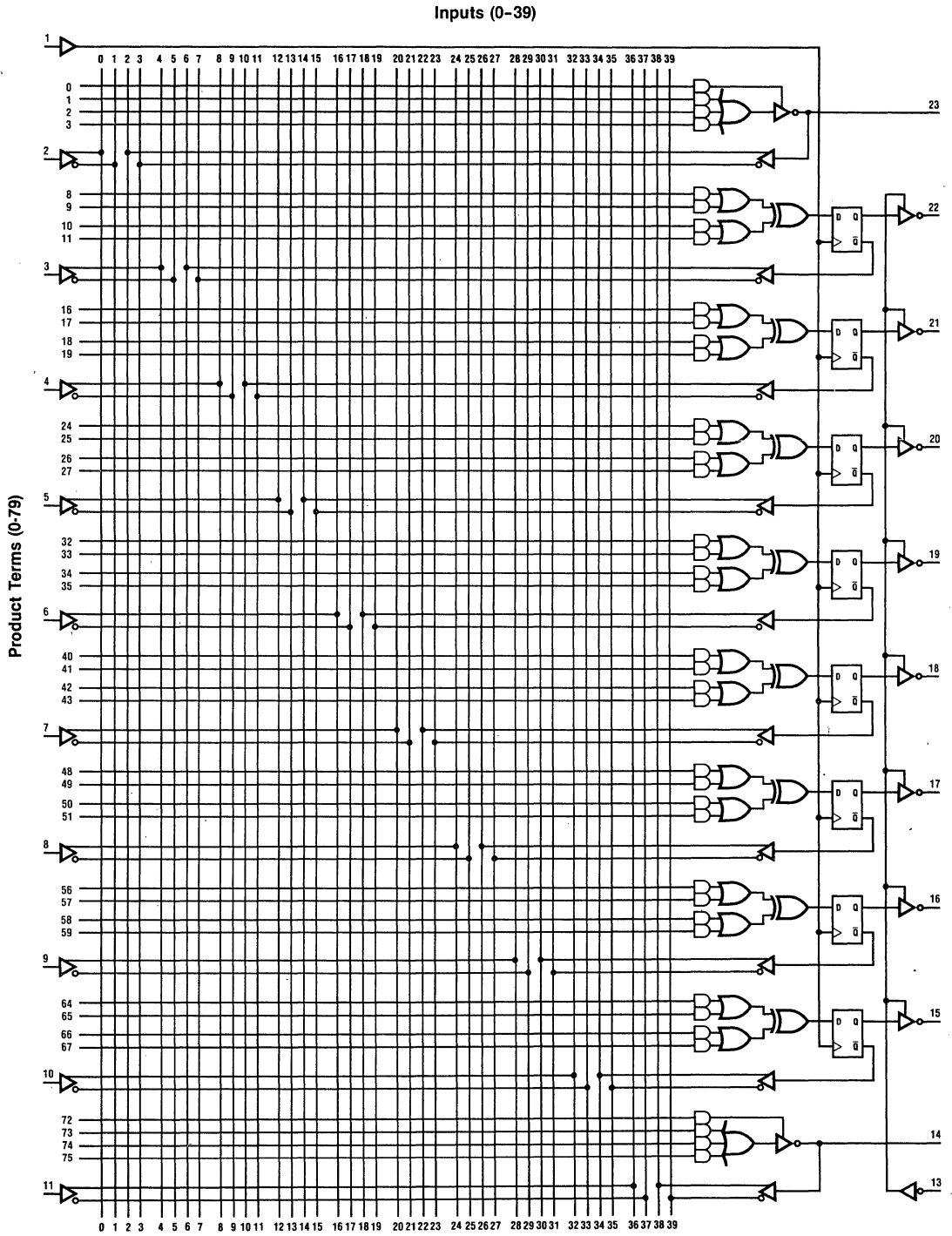
Product Terms (0-79)

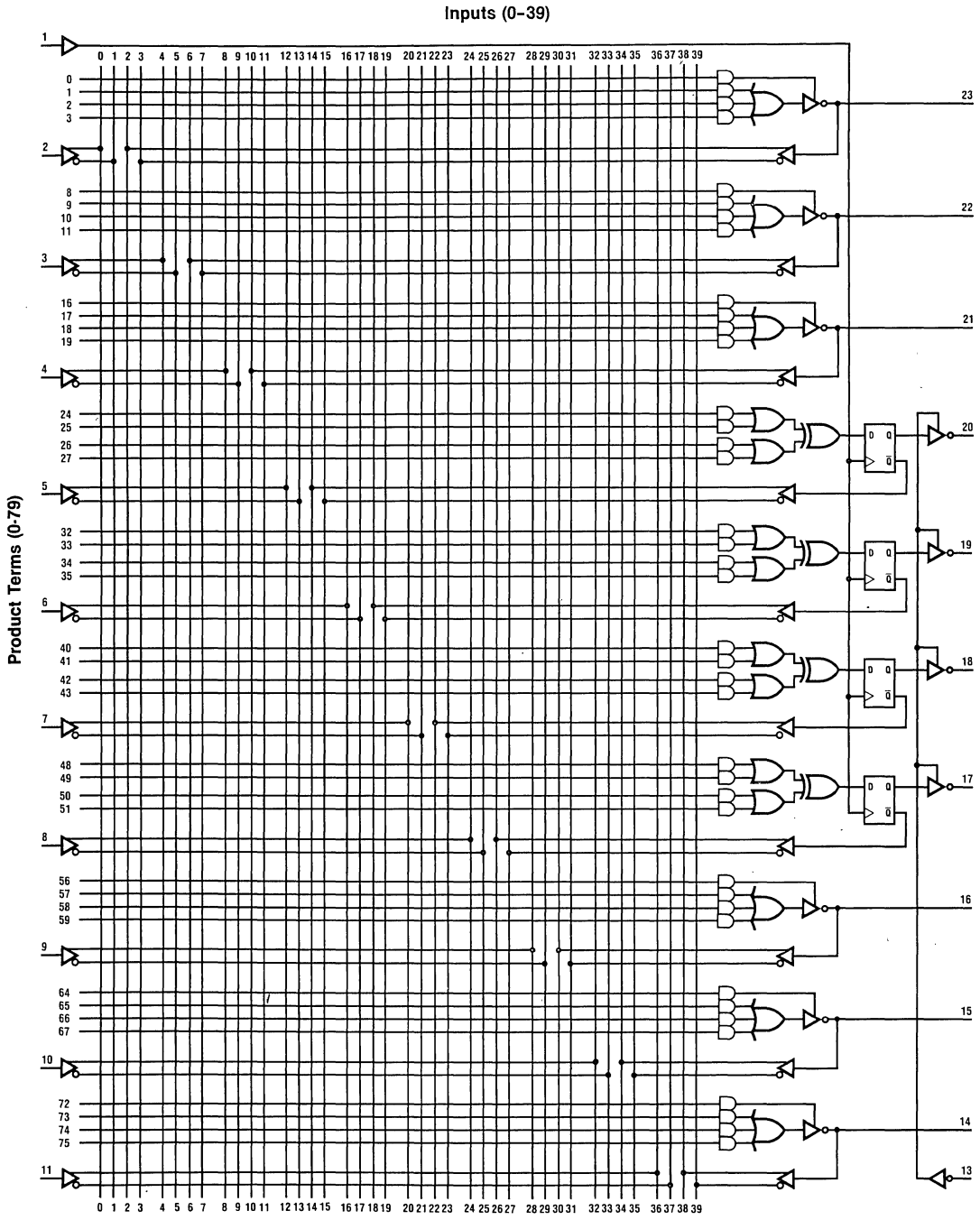


PAL Design

Logic Diagram

DMPAL20X8





PAL LOGIC DIAGRAMS
AND
PROGRAMMING FORMAT
CODING SHEETS
FOR PAL 20 SERIES

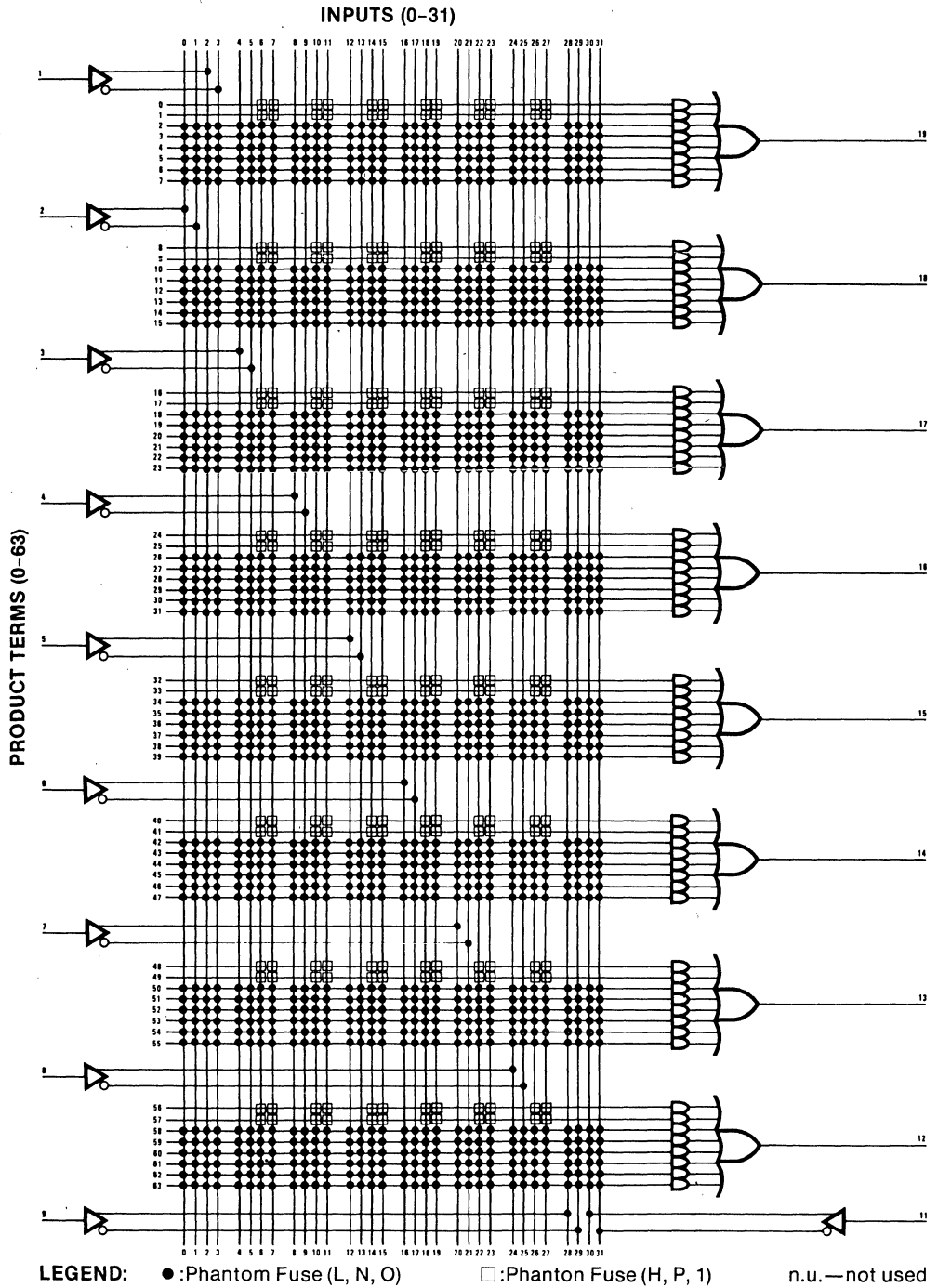


FIGURE 3-32. Logic Diagram, PAL10H8.

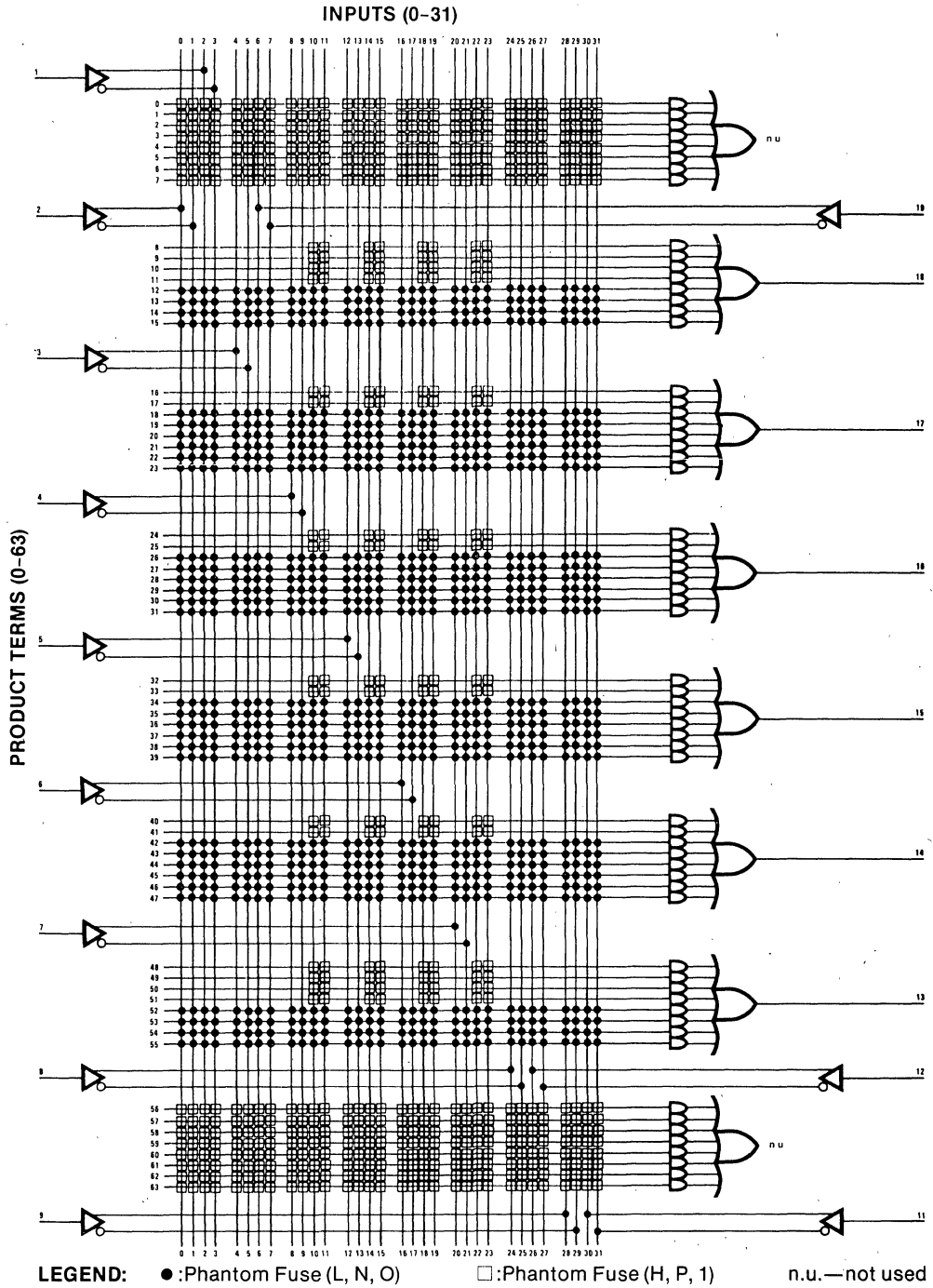


FIGURE 3-34. Logic Diagram, PAL12H6.

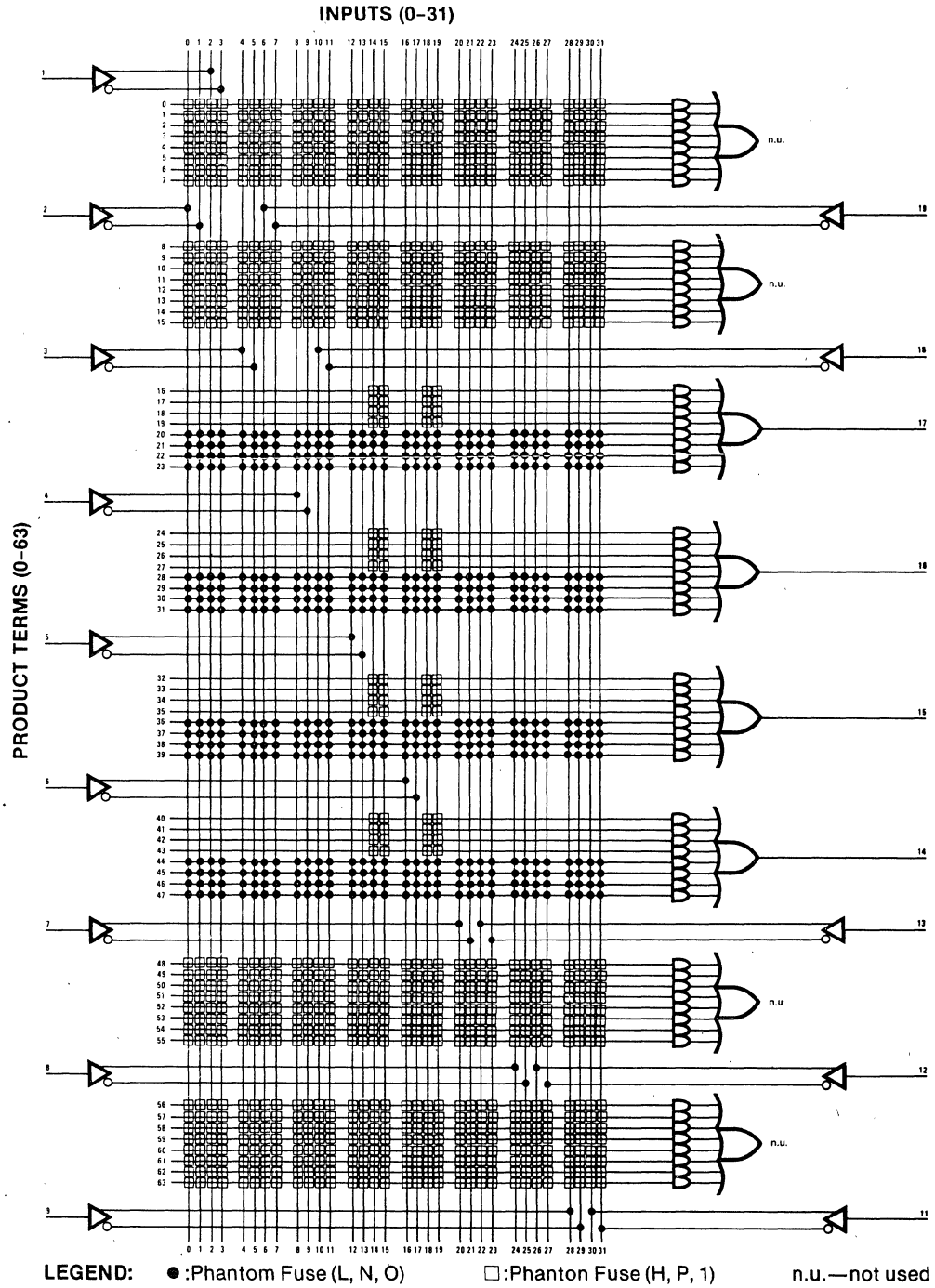


FIGURE 3-36. Logic Diagram, PAL14H4.

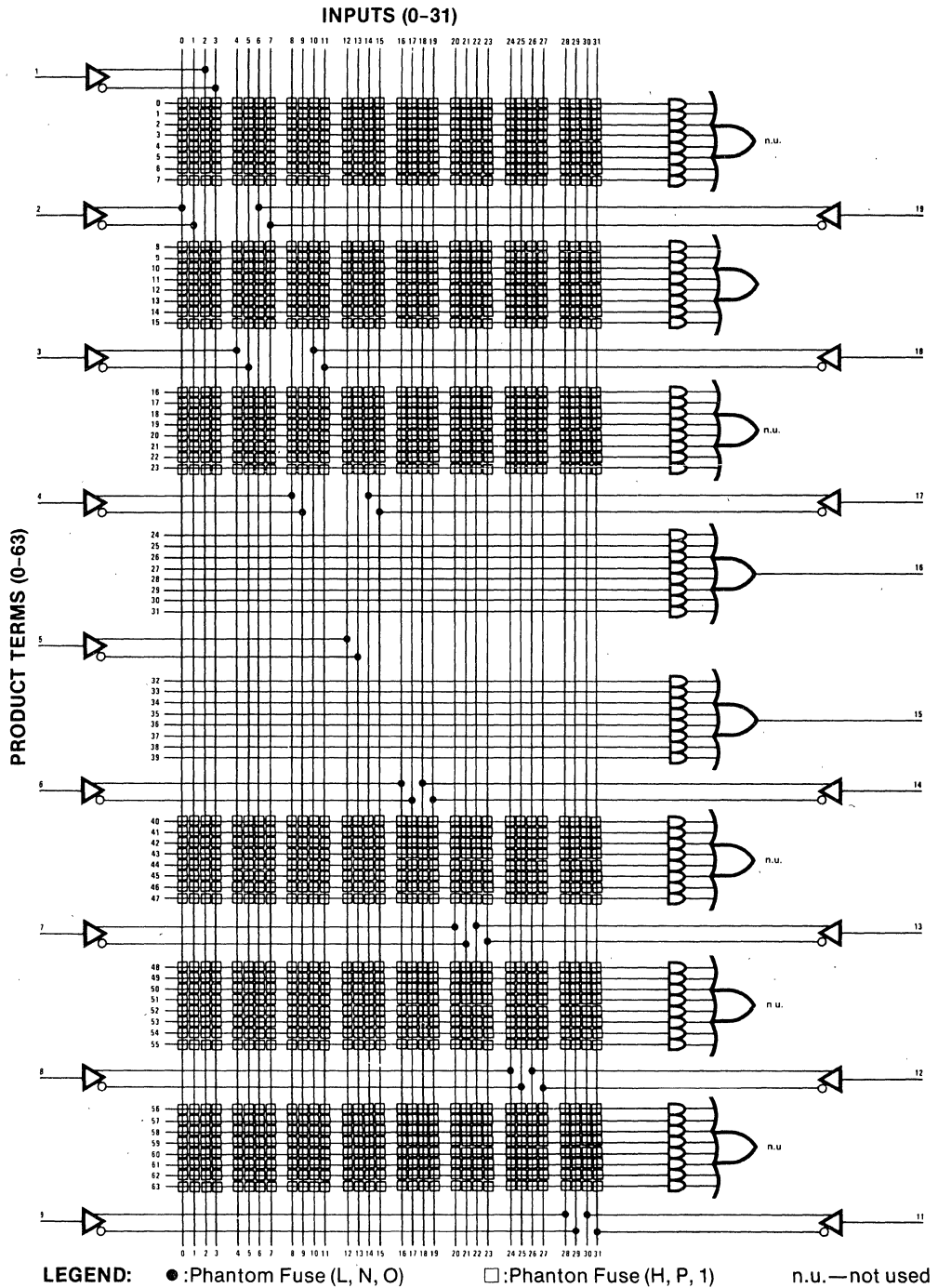


FIGURE 3-38. Logic Diagram, PAL16H2.

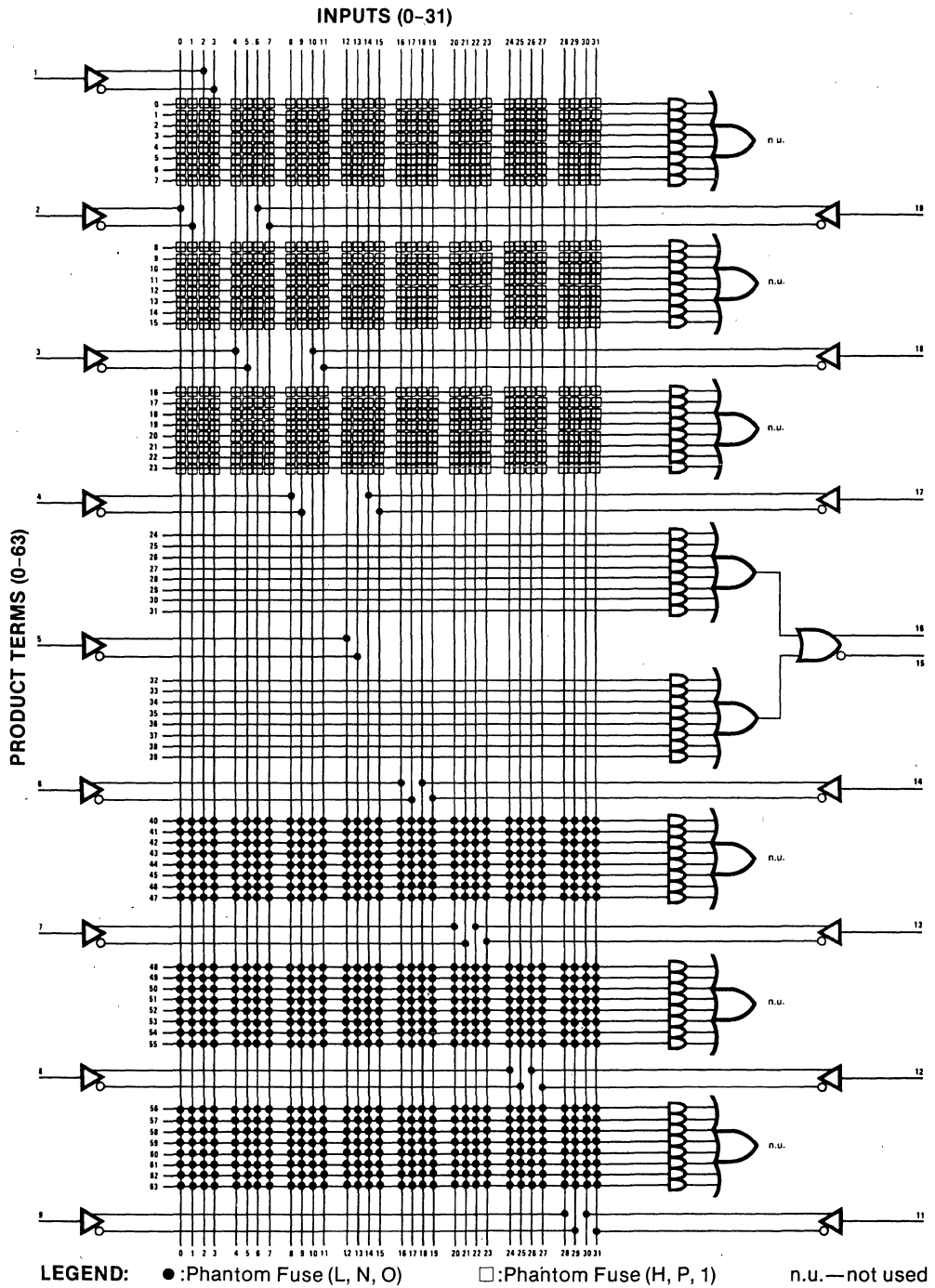


FIGURE 3-40. Logic Diagram, PAL16C1.

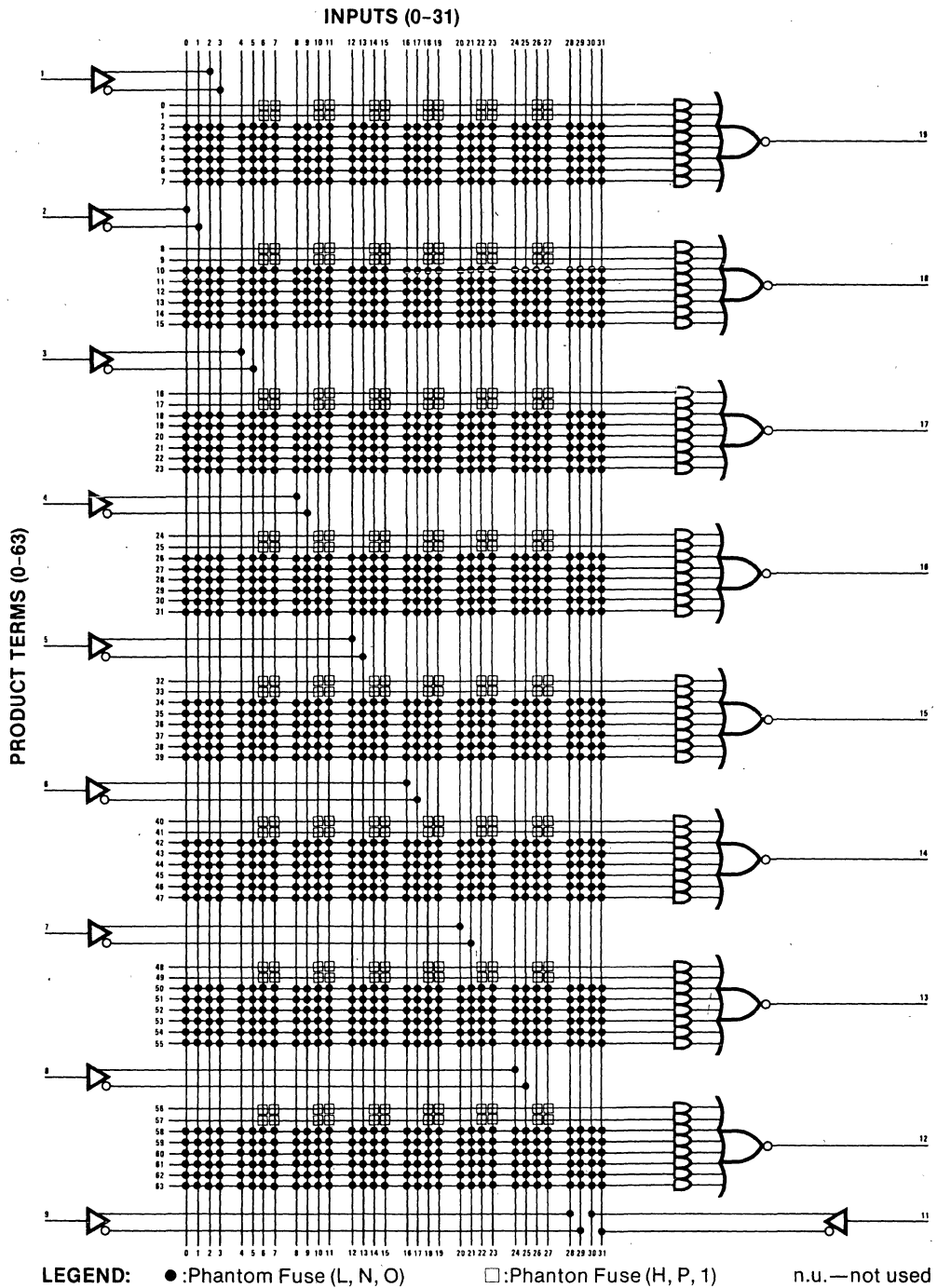


FIGURE 3-42. Logic Diagram, PAL10L8.

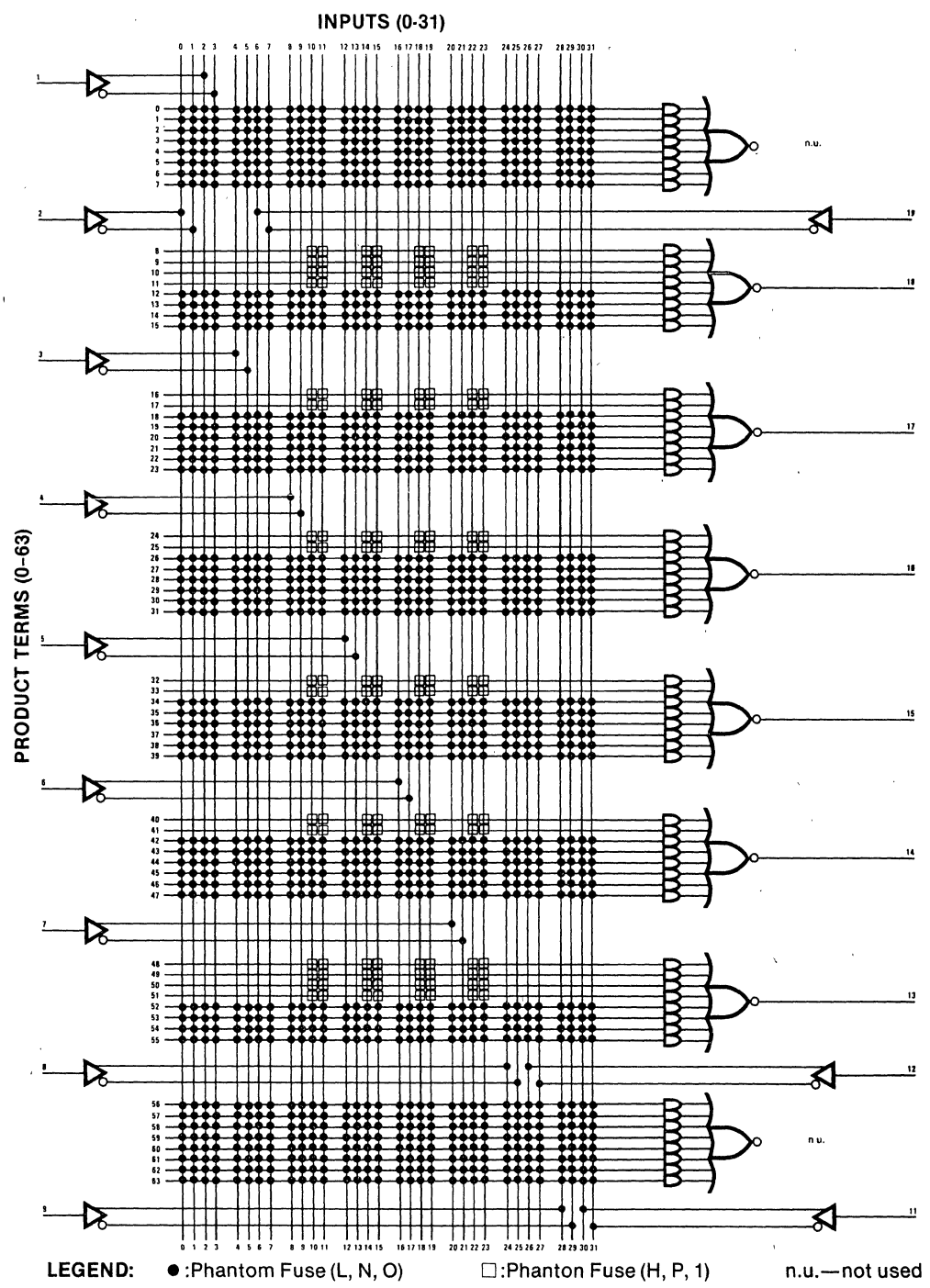


FIGURE 3-44. Logic Diagram, PAL12L6.

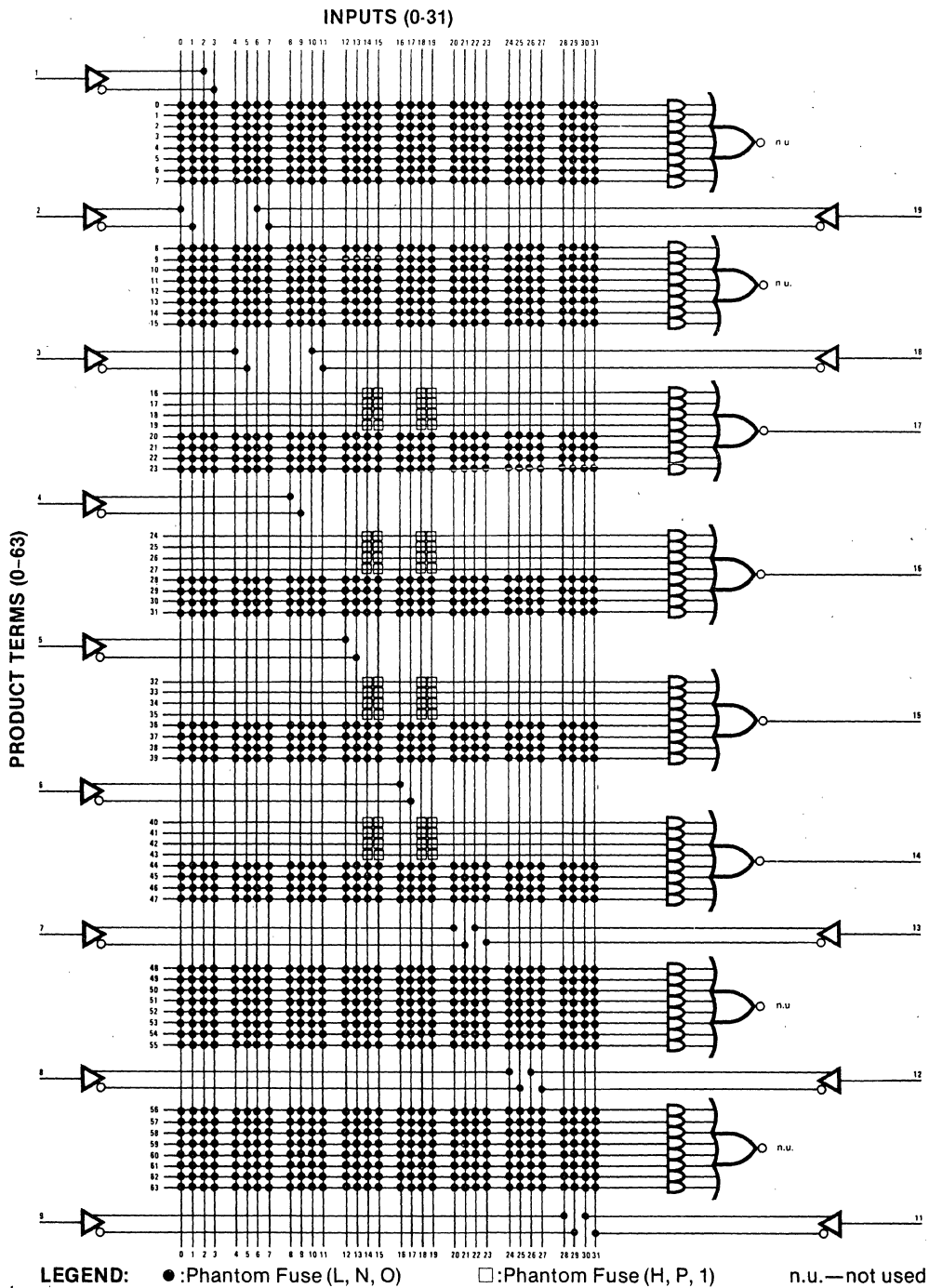


FIGURE 3-46. Logic Diagram, PAL14L4.

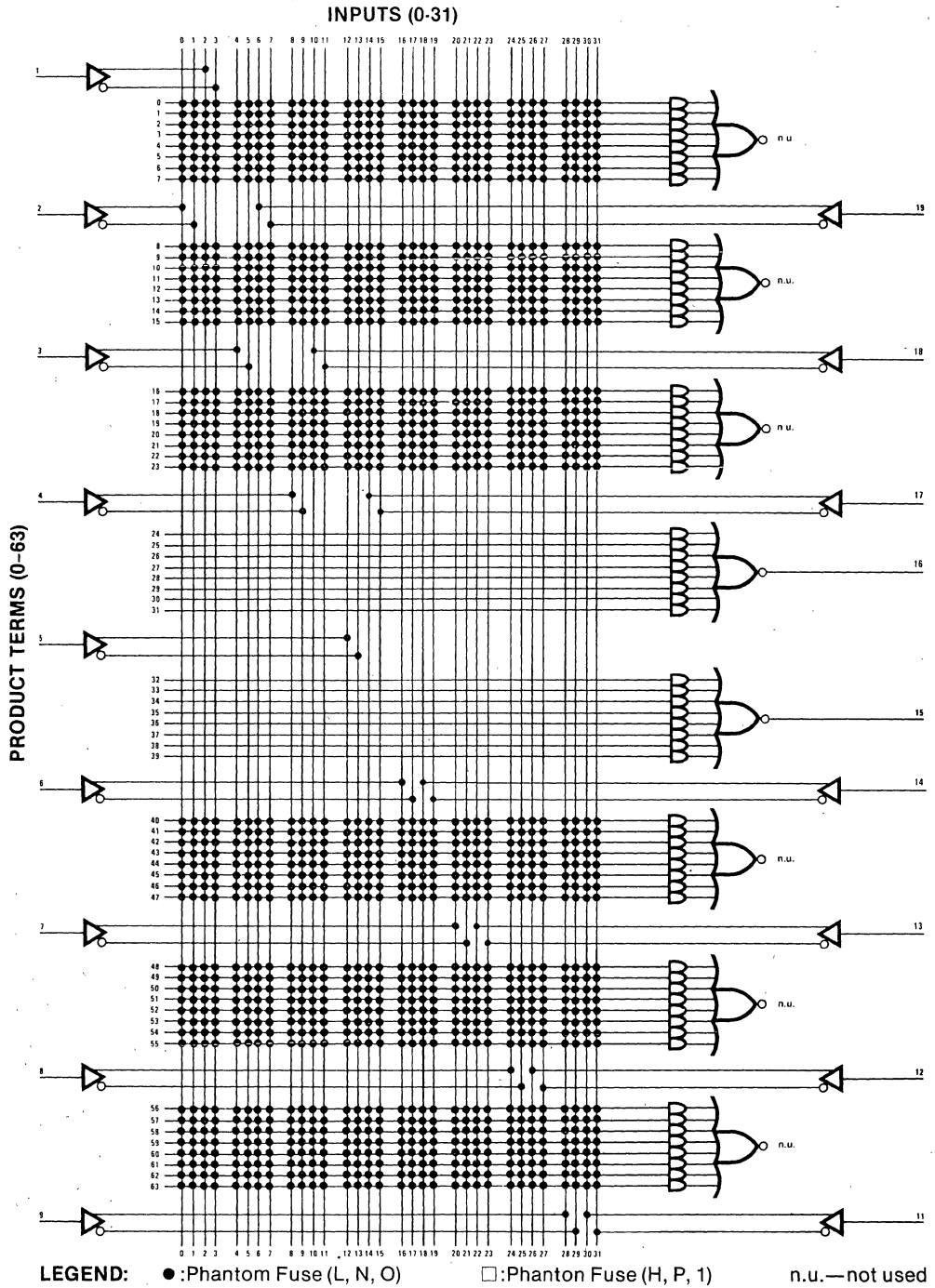


FIGURE 3-48. Logic Diagram, PAL16L2.

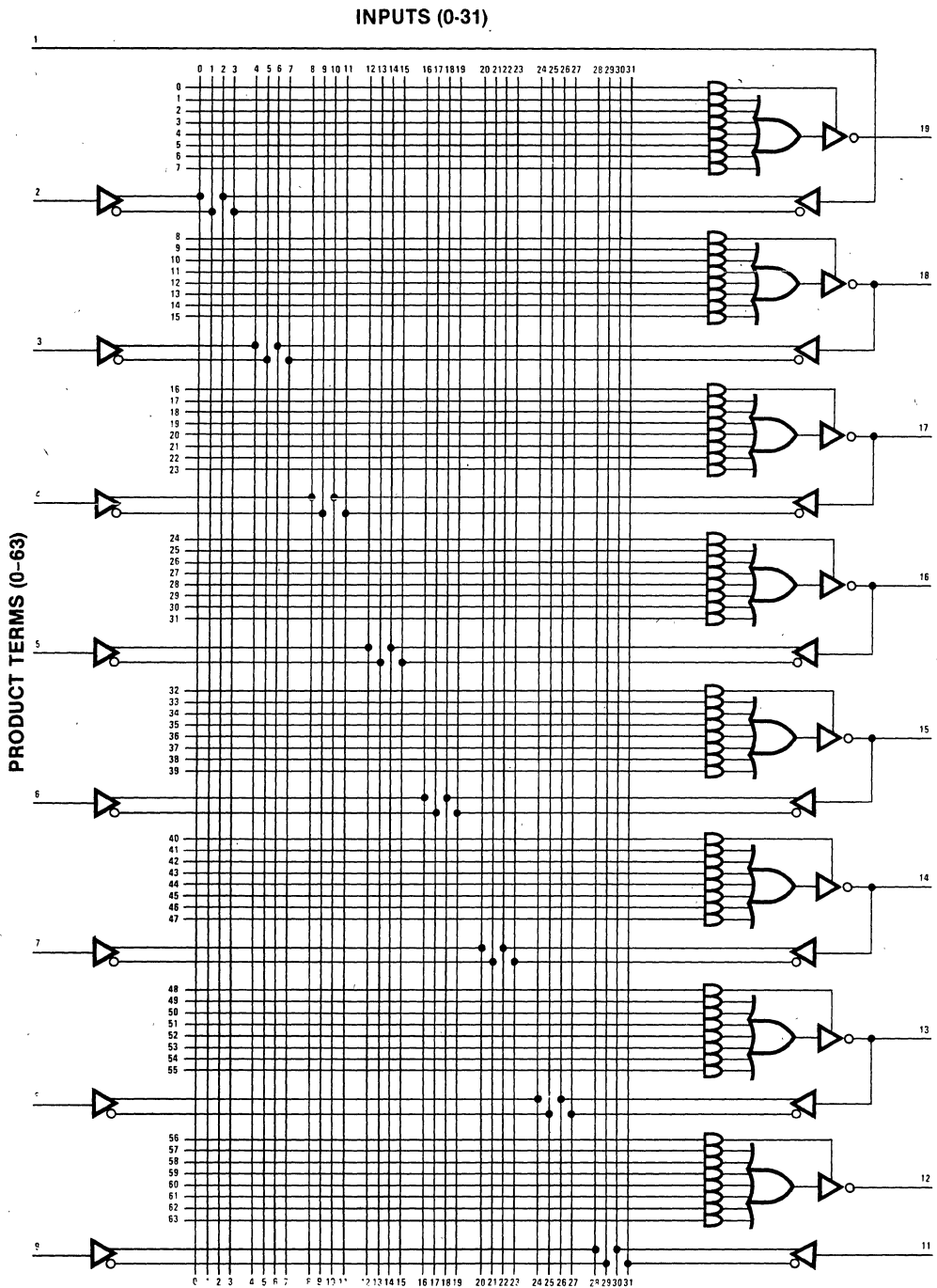


FIGURE 3-50. Logic Diagram, PAL16L8.

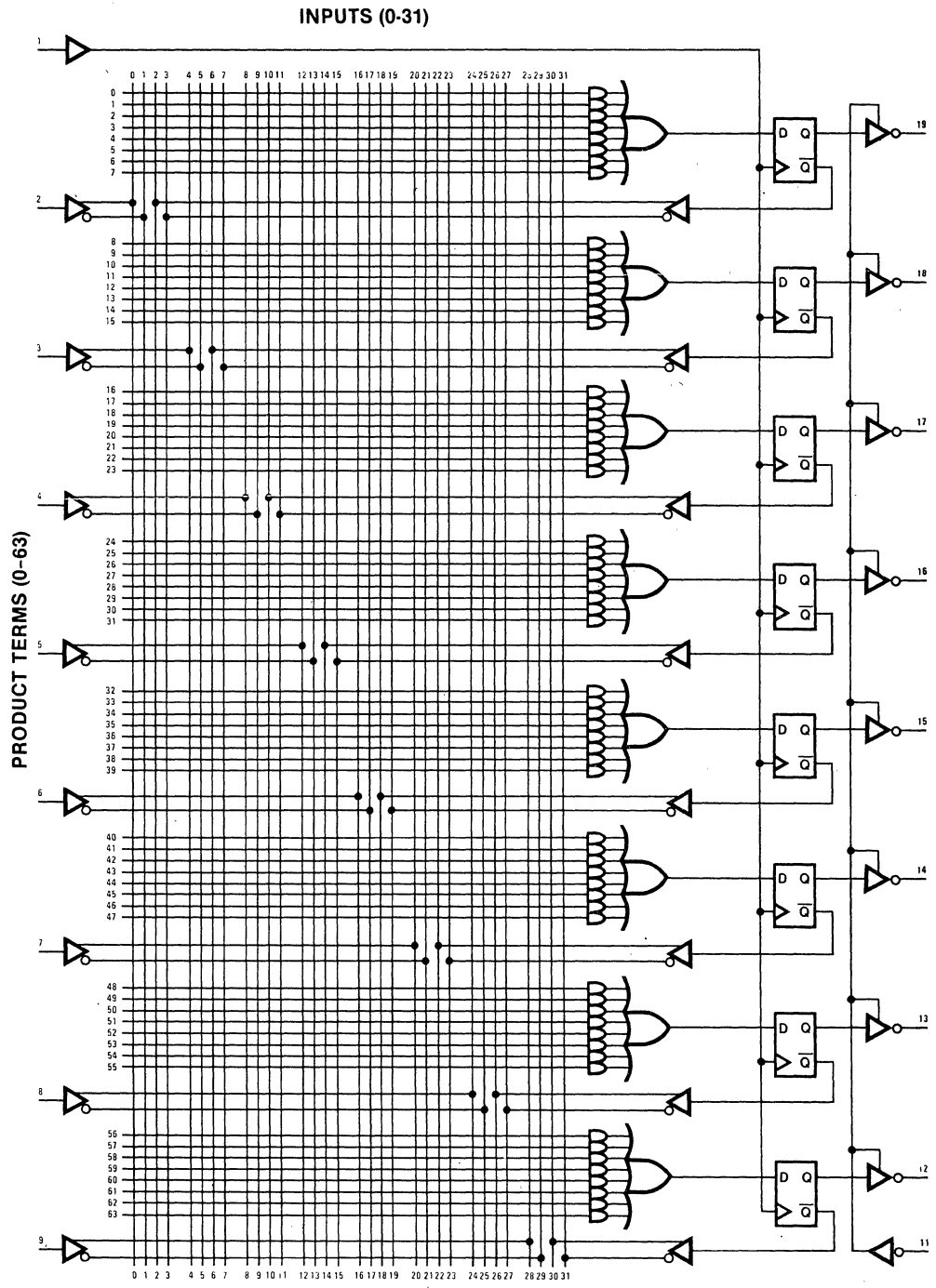


FIGURE 3-52. Logic Diagram, PAL16R8.

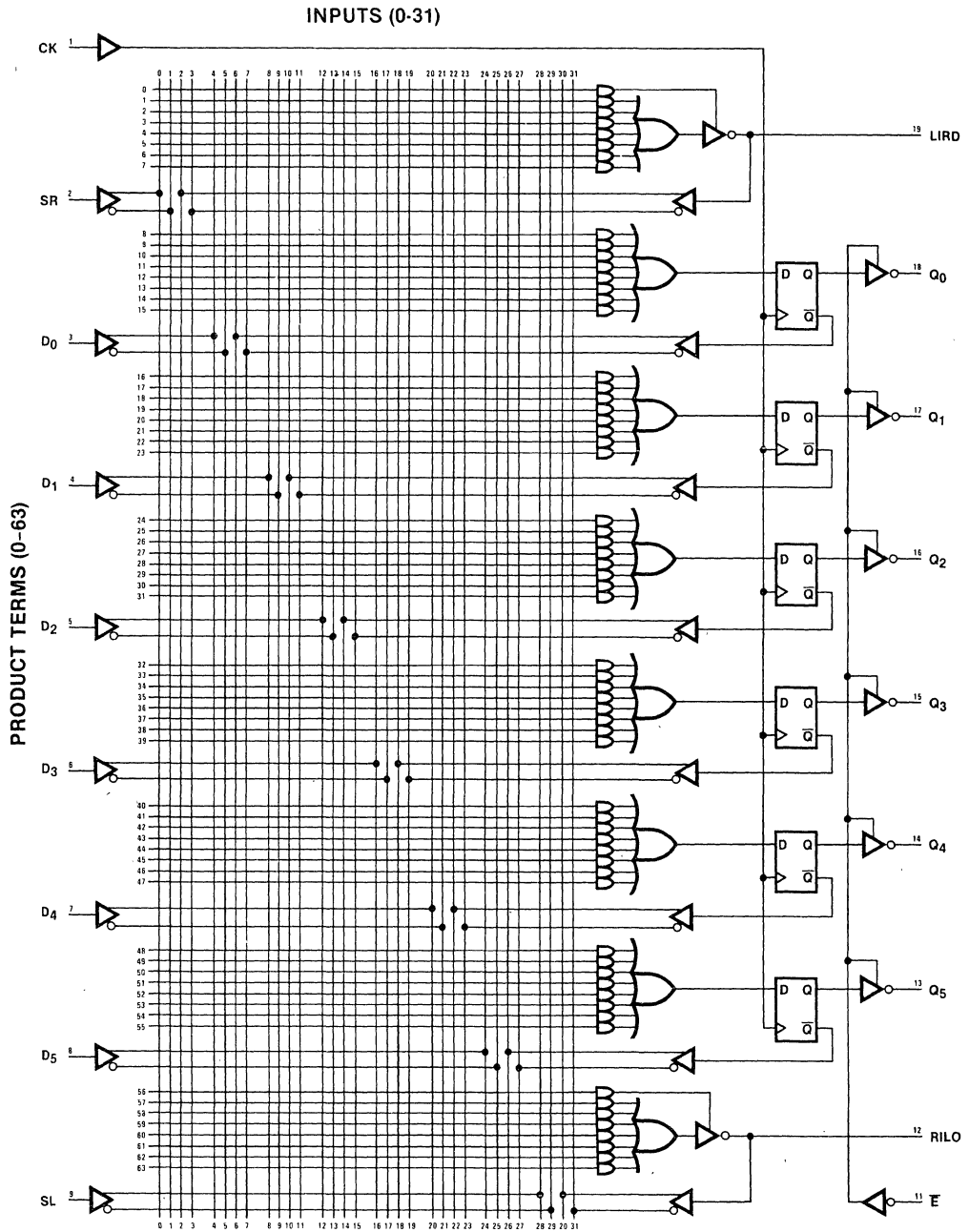


FIGURE 3-54. Logic Diagram, PAL16R6.

Logic Diagram PAL16X4

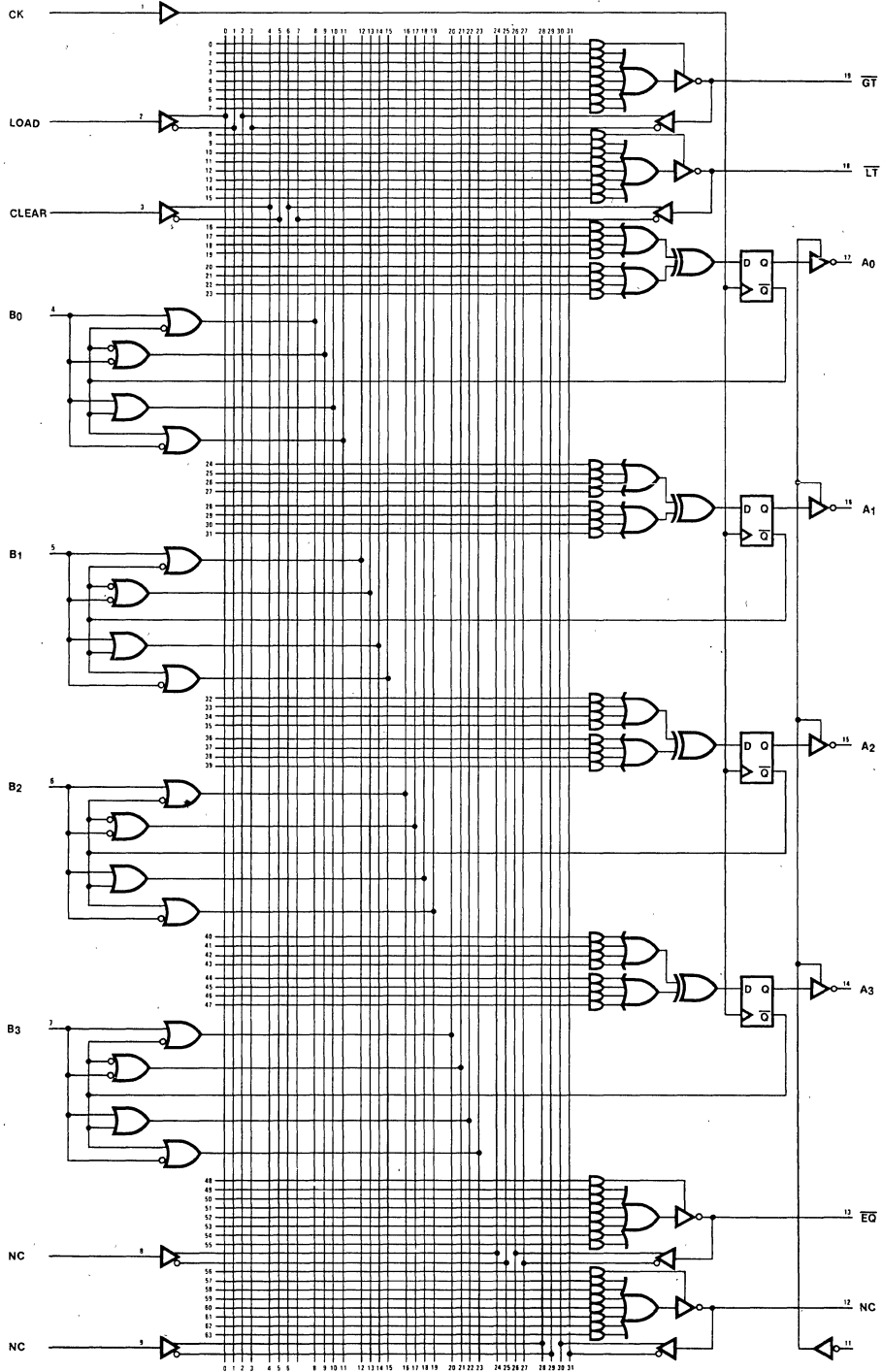


FIGURE 3-58. Logic Diagram, PAL16X4.

Programming Format PAL16R4

PATTERN:

NAME:

PRODUCT TERMS (0-63)

DATE:

INPUTS (0-31)

	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	
WORD	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F	10	11	12	13	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F	
O ₄	24																																
O ₃	16																																
O ₂	8																																
O ₁	0																																
WORD	20	21	22	23	24	25	26	27	28	29	2A	2B	2C	2D	2E	2F	30	31	32	33	34	35	36	37	38	39	3A	3B	3C	3D	3E	3F	
O ₄	25																																
O ₃	17																																
O ₂	9																																
O ₁	1																																
WORD	40	41	42	43	44	45	46	47	48	49	4A	4B	4C	4D	4E	4F	50	51	52	53	54	55	56	57	58	59	5A	5B	5C	5D	5E	5F	
O ₄	26																																
O ₃	18																																
O ₂	10																																
O ₁	2																																
WORD	60	61	62	63	64	65	66	67	68	69	6A	6B	6C	6D	6E	6F	70	71	72	73	74	75	76	77	78	79	7A	7B	7C	7D	7E	7F	
O ₄	27																																
O ₃	19																																
O ₂	11																																
O ₁	3																																
WORD	80	81	82	83	84	85	86	87	88	89	8A	8B	8C	8D	8E	8F	90	91	92	93	94	95	96	97	98	99	9A	9B	9C	9D	9E	9F	
O ₄	28																																
O ₃	20																																
O ₂	12																																
O ₁	4																																
WORD	A0	A1	A2	A3	A4	A5	A6	A7	A8	A9	AA	AB	AC	AD	AE	AF	B0	B1	B2	B3	B4	B5	B6	B7	B8	B9	BA	BB	BC	BD	BE	BF	
O ₄	29																																
O ₃	21																																
O ₂	13																																
O ₁	5																																
WORD	C0	C1	C2	C3	C4	C5	C6	C7	C8	C9	CA	CB	CC	CD	CE	CF	D0	D1	D2	D3	D4	D5	D6	D7	D8	DA	DB	DC	DD	DE	DF		
O ₄	30																																
O ₃	22																																
O ₂	14																																
O ₁	6																																
WORD	E0	E1	E2	E3	E4	E5	E6	E7	E8	E9	EA	EB	EC	ED	EE	EF	F0	F1	F2	F3	F4	F5	F6	F7	F8	F9	FA	FB	FC	FD	FE	FF	
O ₄	31																																
O ₃	23																																
O ₂	15																																
O ₁	7																																
WORD	100	101	102	103	104	105	106	107	108	109	10A	10B	10C	10D	10E	10F	110	111	112	113	114	115	116	117	118	119	11A	11B	11C	11D	11E	11F	
O ₄	56																																
O ₃	48																																
O ₂	40																																
O ₁	32																																
WORD	120	121	122	123	124	125	126	127	128	129	12A	12B	12C	12D	12E	12F	130	131	132	133	134	135	136	137	138	139	13A	13B	13C	13D	13E	13F	
O ₄	57																																
O ₃	49																																
O ₂	41																																
O ₁	33																																
WORD	140	141	142	143	144	145	146	147	148	149	14A	14B	14C	14D	14E	14F	150	151	152	153	154	155	156	157	158	159	15A	15B	15C	15D	15E	15F	
O ₄	58																																
O ₃	50																																
O ₂	42																																
O ₁	34																																
WORD	160	161	162	163	164	165	166	167	168	169	16A	16B	16C	16D	16E	16F	170	171	172	173	174	175	176	177	178	179	17A	17B	17C	17D	17E	17F	
O ₄	59																																
O ₃	51																																
O ₂	43																																
O ₁	35																																
WORD	180	181	182	183	184	185	186	187	188	189	18A	18B	18C	18D	18E	18F	190	191	192	193	194	195	196	197	198	199	19A	19B	19C	19D	19E	19F	
O ₄	60																																
O ₃	52																																
O ₂	44																																
O ₁	36																																
WORD	1A0	1A1	1A2	1A3	1A4	1A5	1A6	1A7	1A8	1A9	1AA	1AB	1AC	1AD	1AE	1AF	1B0	1B1	1B2	1B3	1B4	1B5	1B6	1B7	1B8	1B9	1BA	1BB	1BC	1BD	1BE	1BF	
O ₄	61																																
O ₃	53																																
O ₂	45																																
O ₁	37																																
WORD	1C0	1C1	1C2																														

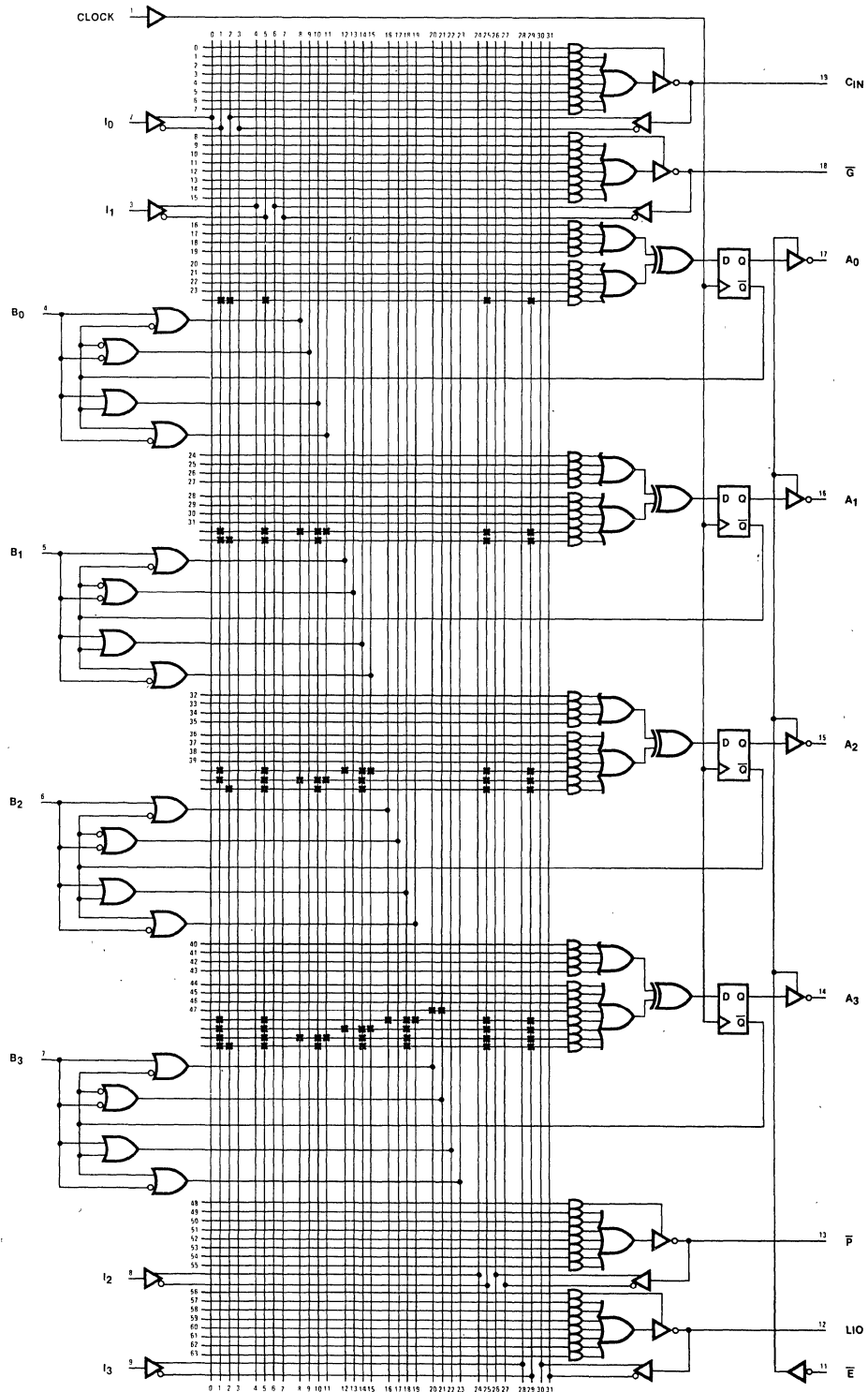


FIGURE 3-60. Logic Diagram, PAL16A4.

Programming Format PAL16R4

PATTERN: _____

NAME: _____

PRODUCT TERMS (0-63)

DATE: _____

INPUTS (0-31)

	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31								
WORD 0	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F	10	11	12	13	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F								
O ₄ 24																																								
O ₃ 16																																								
O ₂ 8																																								
O ₁ 0																																								
WORD 20	20	21	22	23	24	25	26	27	28	29	2A	2B	2C	2D	2E	2F	30	31	32	33	34	35	36	37	38	39	3A	3B	3C	3D	3E	3F								
O ₄ 25																																								
O ₃ 17																																								
O ₂ 9																																								
O ₁ 1																																								
WORD 40	40	41	42	43	44	45	46	47	48	49	4A	4B	4C	4D	4E	4F	50	51	52	53	54	55	56	57	58	59	5A	5B	5C	5D	5E	5F								
O ₄ 26																																								
O ₃ 18																																								
O ₂ 10																																								
O ₁ 2																																								
WORD 60	60	61	62	63	64	65	66	67	68	69	6A	6B	6C	6D	6E	6F	70	71	72	73	74	75	76	77	78	79	7A	7B	7C	7D	7E	7F								
O ₄ 27																																								
O ₃ 19																																								
O ₂ 11																																								
O ₁ 3																																								
WORD 80	80	81	82	83	84	85	86	87	88	89	8A	8B	8C	8D	8E	8F	90	91	92	93	94	95	96	97	98	99	9A	9B	9C	9D	9E	9F								
O ₄ 28																																								
O ₃ 20																																								
O ₂ 12																																								
O ₁ 4																																								
WORD A0	A0	A1	A2	A3	A4	A5	A6	A7	A8	A9	AA	AB	AC	AC	AE	AF	BO	B1	B2	B3	B4	B5	B6	B7	B8	B9	BA	BB	BC	BD	BE	BF								
O ₄ 29																																								
O ₃ 21																																								
O ₂ 13																																								
O ₁ 5																																								
WORD C0	C0	C1	C2	C3	C4	C5	C6	C7	C8	C9	CA	CB	CC	CD	CE	CF	DO	D1	D2	D3	D4	D5	D6	D7	D8	D9	DA	DB	DC	DD	DE	DF								
O ₄ 30																																								
O ₃ 22																																								
O ₂ 14																																								
O ₁ 6																																								
WORD E0	E0	E1	E2	E3	E4	E5	E6	E7	E8	E9	EA	EB	EC	ED	EE	EF	F0	F1	F2	F3	F4	F5	F6	F7	F8	F9	FA	FB	FC	FD	FE	FF								
O ₄ 31																																								
O ₃ 23																																								
O ₂ 15																																								
O ₁ 7																																								
WORD 100	100	101	102	103	104	105	106	107	108	109	10A	10B	10C	10D	10E	10F	110	111	112	113	114	115	116	117	118	119	11A	11B	11C	11D	11E	11F								
O ₄ 56																																								
O ₃ 48																																								
O ₂ 40																																								
O ₁ 32																																								
WORD 120	120	121	122	123	124	125	126	127	128	129	12A	12B	12C	12D	12E	12F	130	131	132	133	134	135	136	137	138	139	13A	13B	13C	13D	13E	13F								
O ₄ 57																																								
O ₃ 49																																								
O ₂ 41																																								
O ₁ 33																																								
WORD 140	140	141	142	143	144	145	146	147	148	149	14A	14B	14C	14D	14E	14F	150	151	152	153	154	155	156	157	158	159	15A	15B	15C	15D	15E	15F								
O ₄ 58																																								
O ₃ 50																																								
O ₂ 42																																								
O ₁ 34																																								
WORD 160	160	161	162	163	164	165	166	167	168	169	16A	16B	16C	16D	16E	16F	170	171	172	173	174	175	176	177	178	179	17A	17B	17C	17D	17E	17F								
O ₄ 59																																								
O ₃ 51																																								
O ₂ 43																																								
O ₁ 35																																								
WORD 180	180	181	182	183	184	185	186	187	188	189	18A	18B	18C	18D																										

Application Suggestions

Using PALs, you may not only replace conventional logic in existing products but also optimize the design of new products. The other chapters of the book discuss the PAL concept and provide information on the advantages gained and the techniques used when designing with PALs. This section shows practical applications that range from simple logic gate replacements to complex control sequencers.

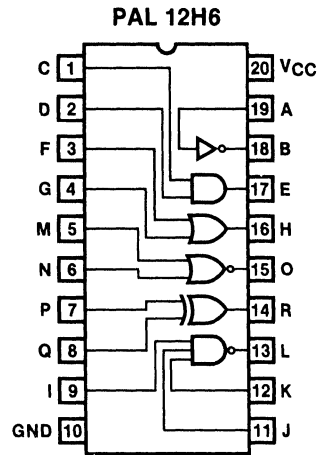
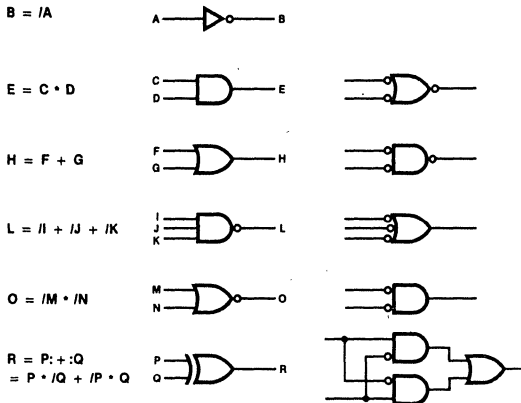
Each example is presented as a complete PAL design, carried through step by step, from the selection of the best PAL to solve the problem to the writing of the logic equations in PALASM notation. In most cases, manual coding is shown as well. This makes the examples complete enough for you to incorporate into your own system designs.

The uses to which PALS can be put are virtually limitless. Let your imagination run wild!

Here is a list of the design ideas you'll find in the ensuing pages:

Example 1-Basic Gates	PAL12H6
Example 2-6-Bit Shift Register	PAL16R6
Control store sequencer	PAL16R4, 16R6
Memory-mapped I/O	PAL16L2
8080 Control Logic for CPU Board ...	PAL16L8
Hexadecimal Decoder & Lamp Driver ..	PAL16L8
Hex Keyboard Scanner	PAL16R4
Micro Floppy Control Logic	PAL14H4
Between-Limits Comparator	PAL16X4, 16C1
Priority Encoder with Register	PAL16R4
Quad 3-line/1-line Data Selector	PAL14H4
4-Bit Counter with Multiplexing	PAL16R4
4-Bit Up/Down Counter with Shift ...	PAL16X4
ALU Accumulator	PAL16X4

EXAMPLE 1: BASIC GATES

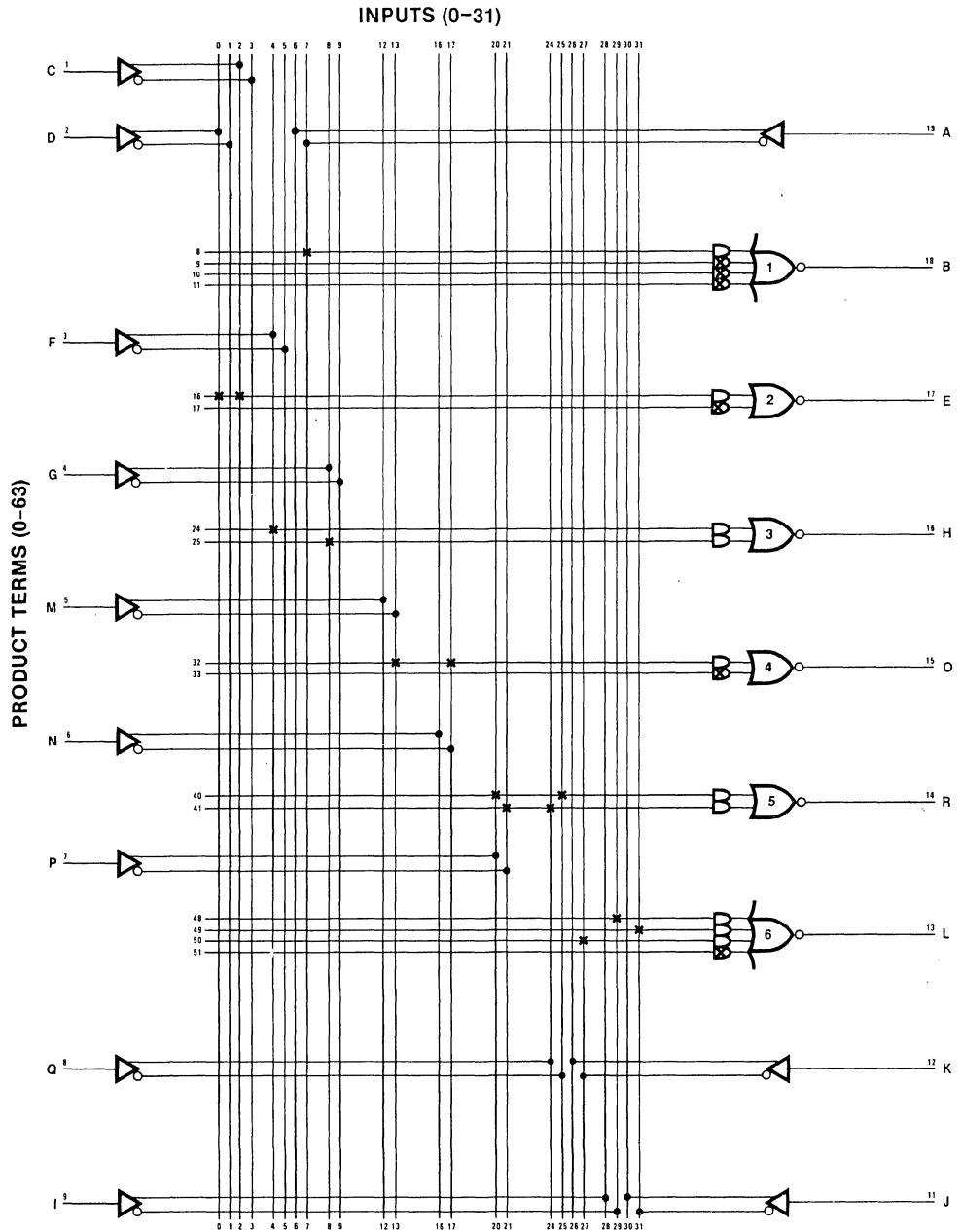


This example demonstrates how fusible logic can implement the basic inverter, AND, OR, NAND, NOR, and exclusive-OR functions. Note the one to one correspondence between conventional logic symbology and PAL logic symbology. The PAL12H6 is selected because it has 12 inputs and 6 outputs. For this this example, the fuse pattern is generated using

- a) PALASM
- b) Manual Programming Format (BHLF) Manual Coding

Basic Gates

Logic Diagram PAL12H6



Manual Coding Basic Gates

Programming Format PAL12H6

PATTERN:

NAME:

PRODUCT TERMS (0-63)

DATE:

INPUTS (0-31)

	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																													
WORD	0	1	2	3	4	5	6	7	8	9	A	B	C	D	E	F	10	11	12	13	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																													
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WORD	20	21	22	23	24	25	26	27	28	29	2A	2B	2C	2D	2E	2F	30	31	32	33	34	35	36	37	38	39	3A	3B	3C	3D	3E	3F	40	41	42	43	44	45	46	47	48	49	50	51	52	53	54	55	56	57	58	59	60	61	62	63																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																																					
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```

          11 1111 1111 2222 2222 2233
0123 4567 8901 2345 6789 0123 4567 8901

0 0000 0000 0000 0000 0000 0000 0000 0000
1 0000 0000 0000 0000 0000 0000 0000 0000
2 0000 0000 0000 0000 0000 0000 0000 0000
3 0000 0000 0000 0000 0000 0000 0000 0000
4 0000 0000 0000 0000 0000 0000 0000 0000
5 0000 0000 0000 0000 0000 0000 0000 0000
6 0000 0000 0000 0000 0000 0000 0000 0000
7 0000 0000 0000 0000 0000 0000 0000 0000

8 ---- -X- --00 --00 --00 --00 ---- /A
9 XXXX XXXX XX00 XX00 XX00 XX00 XXXX XXXX
10 XXXX XXXX XX00 XX00 XX00 XX00 XXXX XXXX
11 XXXX XXXX XX00 XX00 XX00 XX00 XXXX XXXX
12 0000 0000 0000 0000 0000 0000 0000 0000
13 0000 0000 0000 0000 0000 0000 0000 0000
14 0000 0000 0000 0000 0000 0000 0000 0000
15 0000 0000 0000 0000 0000 0000 0000 0000

16 X-X- ---- --00 --00 --00 --00 ---- C*D
17 XXXX XXXX XX00 XX00 XX00 XX00 XXXX XXXX
18 0000 0000 0000 0000 0000 0000 0000 0000
19 0000 0000 0000 0000 0000 0000 0000 0000
20 0000 0000 0000 0000 0000 0000 0000 0000
21 0000 0000 0000 0000 0000 0000 0000 0000
22 0000 0000 0000 0000 0000 0000 0000 0000
23 0000 0000 0000 0000 0000 0000 0000 0000

24 ---- X--- --00 --00 --00 --00 ---- F
25 ---- ---- X-00 --00 --00 --00 ---- G
26 0000 0000 0000 0000 0000 0000 0000 0000
27 0000 0000 0000 0000 0000 0000 0000 0000
28 0000 0000 0000 0000 0000 0000 0000 0000
29 0000 0000 0000 0000 0000 0000 0000 0000
30 0000 0000 0000 0000 0000 0000 0000 0000
31 0000 0000 0000 0000 0000 0000 0000 0000

32 ---- ---- --00 -X00 -X00 --00 ---- /M*/N
33 XXXX XXXX XX00 XX00 XX00 XX00 XXXX XXXX
34 0000 0000 0000 0000 0000 0000 0000 0000
35 0000 0000 0000 0000 0000 0000 0000 0000
36 0000 0000 0000 0000 0000 0000 0000 0000
37 0000 0000 0000 0000 0000 0000 0000 0000
38 0000 0000 0000 0000 0000 0000 0000 0000
39 0000 0000 0000 0000 0000 0000 0000 0000

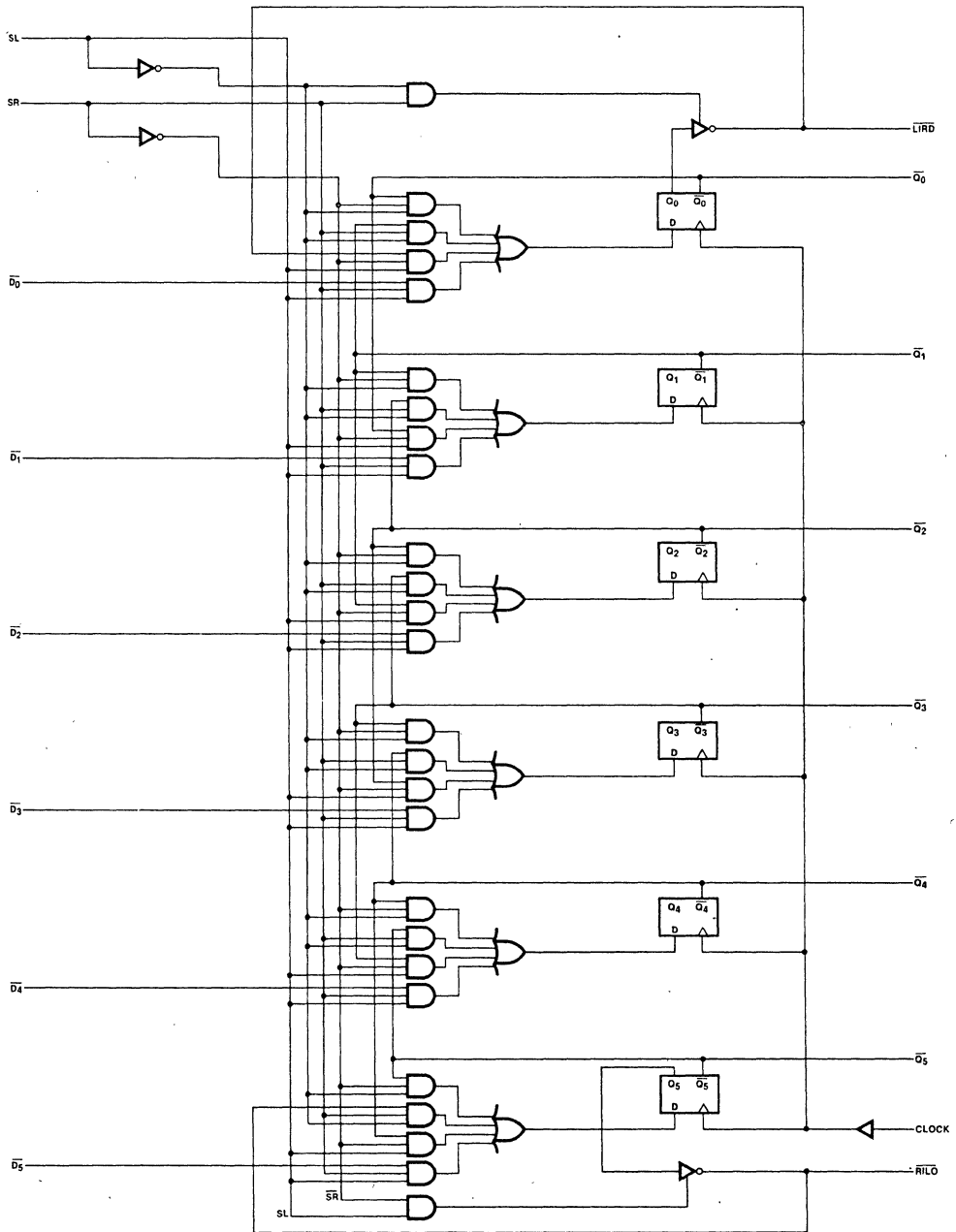
40 ---- ---- --00 --00 --00 X-00 -X-- ---- P*/Q
41 ---- ---- --00 --00 --00 -X00 X--- ---- /P*Q
42 0000 0000 0000 0000 0000 0000 0000 0000
43 0000 0000 0000 0000 0000 0000 0000 0000
44 0000 0000 0000 0000 0000 0000 0000 0000
45 0000 0000 0000 0000 0000 0000 0000 0000
46 0000 0000 0000 0000 0000 0000 0000 0000
47 0000 0000 0000 0000 0000 0000 0000 0000

48 ---- ---- --00 --00 --00 --00 ---- -X-- /I
49 ---- ---- --00 --00 --00 --00 ---- ---X /J
50 ---- ---- --00 --00 --00 --00 ---- ---X /K
51 XXXX XXXX XX00 XX00 XX00 XX00 XXXX XXXX
52 0000 0000 0000 0000 0000 0000 0000 0000
53 0000 0000 0000 0000 0000 0000 0000 0000
54 0000 0000 0000 0000 0000 0000 0000 0000
55 0000 0000 0000 0000 0000 0000 0000 0000

56 0000 0000 0000 0000 0000 0000 0000 0000
57 0000 0000 0000 0000 0000 0000 0000 0000
58 0000 0000 0000 0000 0000 0000 0000 0000
59 0000 0000 0000 0000 0000 0000 0000 0000
60 0000 0000 0000 0000 0000 0000 0000 0000
61 0000 0000 0000 0000 0000 0000 0000 0000
62 0000 0000 0000 0000 0000 0000 0000 0000
63 0000 0000 0000 0000 0000 0000 0000 0000
    
```

LEGEND: X : FUSE NOT BLOWN (L,N,0) - : FUSE BLOWN (H,P,1)
 0 : PHANTOM FUSE (L,N,0) O : PHANTOM FUSE (H,P,1)

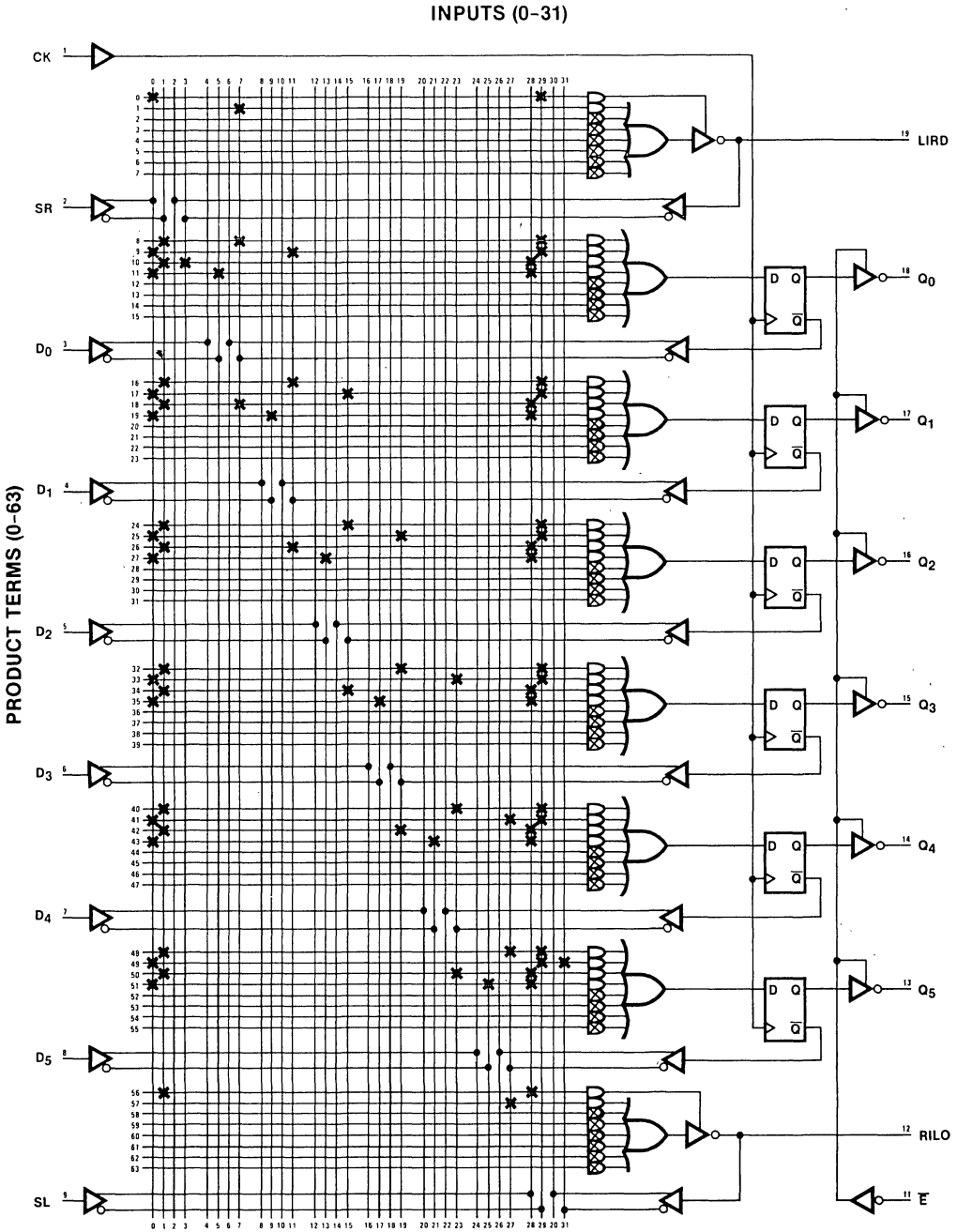
**EXAMPLE 2:
6-BIT SHIFT REGISTER WITH THREE-STATE OUTPUTS**



Manual Coding: 6-Bit Shift Register with Three-State Outputs

Logic Diagram PAL16R6

Application Suggestions



Manual Coding: 6-Bit Shift Register with Three-State Outputs

INPUTS (0-31)

Programming Format PAL12H6

PATTERN:

NAME:

PRODUCT TERMS (0-63)

DATE:

WORD	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31																						
0 ₄	24	25	26	27	28	29	30	31	A	B	C	D	E	F	10	11	12	13	14	15	16	17	18	19	1A	1B	1C	1D	1E	1F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	2A	2B	2C	2D	2E	2F	30	31	32	33	34	35	36	37	38	39	3A	3B	3C	3D	3E	3F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	4A	4B	4C	4D	4E	4F	50	51	52	53	54	55	56	57	58	59	5A	5B	5C	5D	5E	5F								
0 ₁	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	6A	6B	6C	6D	6E	6F	70	71	72	73	74	75	76	77	78	79	7A	7B	7C	7D	7E	7F
0 ₄	24	25	26	27	28	29	30	31	8A	8B	8C	8D	8E	8F	90	91	92	93	94	95	96	97	98	99	9A	9B	9C	9D	9E	9F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	10A	10B	10C	10D	10E	10F	110	111	112	113	114	115	116	117	118	119	11A	11B	11C	11D	11E	11F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	12A	12B	12C	12D	12E	12F	130	131	132	133	134	135	136	137	138	139	13A	13B	13C	13D	13E	13F								
0 ₁	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	14A	14B	14C	14D	14E	14F	150	151	152	153	154	155	156	157	158	159	15A	15B	15C	15D	15E	15F
0 ₄	24	25	26	27	28	29	30	31	16A	16B	16C	16D	16E	16F	170	171	172	173	174	175	176	177	178	179	17A	17B	17C	17D	17E	17F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	18A	18B	18C	18D	18E	18F	190	191	192	193	194	195	196	197	198	199	19A	19B	19C	19D	19E	19F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	20A	20B	20C	20D	20E	20F	210	211	212	213	214	215	216	217	218	219	21A	21B	21C	21D	21E	21F								
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0 ₄	24	25	26	27	28	29	30	31	24A	24B	24C	24D	24E	24F	250	251	252	253	254	255	256	257	258	259	25A	25B	25C	25D	25E	25F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	26A	26B	26C	26D	26E	26F	270	271	272	273	274	275	276	277	278	279	27A	27B	27C	27D	27E	27F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	28A	28B	28C	28D	28E	28F	290	291	292	293	294	295	296	297	298	299	29A	29B	29C	29D	29E	29F								
0 ₁	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	30A	30B	30C	30D	30E	30F	310	311	312	313	314	315	316	317	318	319	31A	31B	31C	31D	31E	31F
0 ₄	24	25	26	27	28	29	30	31	32A	32B	32C	32D	32E	32F	330	331	332	333	334	335	336	337	338	339	33A	33B	33C	33D	33E	33F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	34A	34B	34C	34D	34E	34F	350	351	352	353	354	355	356	357	358	359	35A	35B	35C	35D	35E	35F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	36A	36B	36C	36D	36E	36F	370	371	372	373	374	375	376	377	378	379	37A	37B	37C	37D	37E	37F								
0 ₁	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	38A	38B	38C	38D	38E	38F	390	391	392	393	394	395	396	397	398	399	39A	39B	39C	39D	39E	39F
0 ₄	24	25	26	27	28	29	30	31	40A	40B	40C	40D	40E	40F	410	411	412	413	414	415	416	417	418	419	41A	41B	41C	41D	41E	41F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	42A	42B	42C	42D	42E	42F	430	431	432	433	434	435	436	437	438	439	43A	43B	43C	43D	43E	43F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	44A	44B	44C	44D	44E	44F	450	451	452	453	454	455	456	457	458	459	45A	45B	45C	45D	45E	45F								
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0 ₄	24	25	26	27	28	29	30	31	48A	48B	48C	48D	48E	48F	490	491	492	493	494	495	496	497	498	499	49A	49B	49C	49D	49E	49F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	50A	50B	50C	50D	50E	50F	510	511	512	513	514	515	516	517	518	519	51A	51B	51C	51D	51E	51F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	52A	52B	52C	52D	52E	52F	530	531	532	533	534	535	536	537	538	539	53A	53B	53C	53D	53E	53F								
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0 ₄	24	25	26	27	28	29	30	31	56A	56B	56C	56D	56E	56F	570	571	572	573	574	575	576	577	578	579	57A	57B	57C	57D	57E	57F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	58A	58B	58C	58D	58E	58F	590	591	592	593	594	595	596	597	598	599	59A	59B	59C	59D	59E	59F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	60A	60B	60C	60D	60E	60F	610	611	612	613	614	615	616	617	618	619	61A	61B	61C	61D	61E	61F								
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0 ₄	24	25	26	27	28	29	30	31	64A	64B	64C	64D	64E	64F	650	651	652	653	654	655	656	657	658	659	65A	65B	65C	65D	65E	65F																								
0 ₃	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	66A	66B	66C	66D	66E	66F	670	671	672	673	674	675	676	677	678	679	67A	67B	67C	67D	67E	67F																
0 ₂	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	68A	68B	68C	68D	68E	68F	690	691	692	693	694	695	696	697	698	699	69A	69B	69C	69D	69E	69F								
0 ₁	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	70A	70B	70C	70D	70E	70F	710	711	712	713	714											

**PALASM Output: 6-Bit Shift Register
with Three-State Outputs**

Fuse Plot PAL16R6

```

          11 111 1111 2222 2222 2233
0123 4567 8901 2345 6789 0123 4567 8901

0 X--- ---- ---- ---- ---- ---- -X-- SR*/SL
1 ---- --X- ---- ---- ---- ---- ---- /Q0
2 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
3 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
4 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
5 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
6 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
7 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX

8 -X-- ---- -X- ---- ---- ---- ---- -X-- /SR*/SL*/Q0
9 X--- ---- --X- ---- ---- ---- ---- -X-- SR*/SL*/Q1
10 -X-X ---- ---- ---- ---- ---- ---- X--- /SR*/SL*/LIRO
11 X--- -X- ---- ---- ---- ---- ---- X--- SR*/SL*/D0
12 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
13 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
14 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
15 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX

16 -X-- ---- --X- ---- ---- ---- ---- -X-- /SR*/SL*/Q1
17 X--- ---- ---- --X- ---- ---- ---- -X-- SR*/SL*/Q2
18 -X- ---- -X- ---- ---- ---- ---- X--- /SR*/SL*/Q0
19 X--- ---- -X- ---- ---- ---- ---- X--- SR*/SL*/D1
20 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
21 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
22 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
23 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX

24 -X-- ---- ---- --X- ---- ---- ---- -X-- /SR*/SL*/Q2
25 X--- ---- ---- ---- --X- ---- ---- -X-- SR*/SL*/Q3
26 -X- ---- -X- ---- ---- ---- ---- X--- /SR*/SL*/Q1
27 X--- ---- ---- -X- ---- ---- ---- X--- SR*/SL*/D2
28 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
29 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
30 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
31 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX

32 -X-- ---- ---- ---- --X- ---- ---- -X-- /SR*/SL*/Q3
33 X--- ---- ---- ---- ---- --X- ---- -X-- SR*/SL*/Q4
34 -X- ---- -X- ---- ---- ---- X--- /SR*/SL*/Q2
35 X--- ---- ---- ---- -X- ---- ---- X--- SR*/SL*/D3
36 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
37 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
38 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
39 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX

40 -X-- ---- ---- ---- ---- --X- ---- -X-- /SR*/SL*/Q4
41 X--- ---- ---- ---- ---- ---- --X- -X-- SR*/SL*/Q5
42 -X- ---- -X- ---- ---- ---- X--- /SR*/SL*/Q3
43 X--- ---- ---- ---- ---- -X- ---- X--- SR*/SL*/D4
44 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
45 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
46 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
47 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX

48 -X-- ---- ---- ---- ---- ---- -X- -X-- /SR*/SL*/Q5
49 X--- ---- ---- ---- ---- ---- -X-X SR*/SL*/RILO
50 -X- ---- ---- ---- ---- ---- X--- /SR*/SL*/Q4
51 X--- ---- ---- ---- ---- ---- -X- -X-- SR*/SL*/D5
52 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
53 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
54 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
55 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX

56 -X-- ---- ---- ---- ---- ---- X--- /SR*/SL
57 ---- ---- ---- ---- ---- ---- -X- /Q5
58 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
59 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
60 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
61 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
62 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX
63 XXXX XXXX XXXX XXXX XXXX XXXX XXXX XXXX

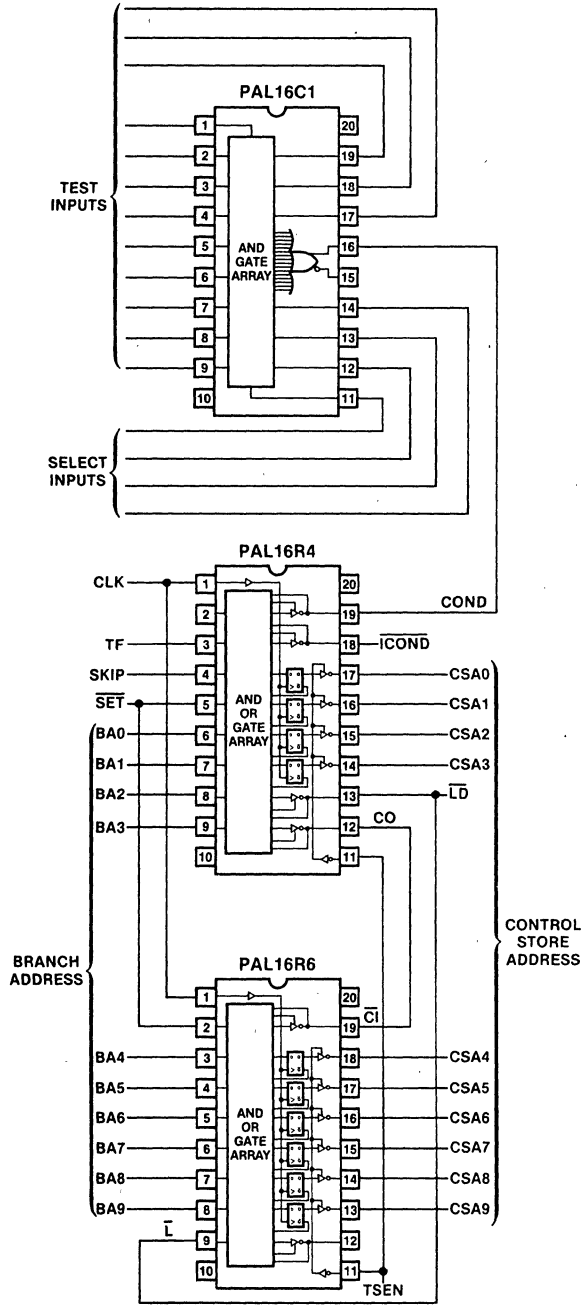
```

LEGEND: X : FUSE NOT BLOWN (L,N,0) - : FUSE BLOWN (H,P,1)

CONTROL STORE SEQUENCER

Solutions to control store sequencing are as varied as the problems that are solved by microprogrammed hardware. The traditional approach tends to be horizontally structured,

whereas the application described here is designed for use with a vertical control store structure. The vertical control store has narrow control fields and may share field functions to increase efficiency. It is fast.



Control Store Sequencer Logic Schematic.

How It Works

This control store sequencer is designed to use a minimum of control bits while providing sufficient sequencing flexibility. Only three bits are required for the basic sequencer control. They make three things happen:

CSA = CSA + 1 Increment control store address
 CSA = CSA + 2 A sort of branch instruction
 CSA = BA Load a branch address

The three control bits are SKIP, COND, and TF.

Skip defines whether the sequencer will skip or load.

Cond is the condition that is tested to see if the sequencer executed the operation defined by Skip.

TF defines whether Cond is tested true or false.

Table below lists all of the states the sequencer can assume.

Sequencer States

Skip	Cond	TF	Operation
0	0	0	Load
0	0	1	Increment
0	1	0	Increment
0	1	1	Load
1	0	0	Skip
1	0	1	Increment
1	1	0	Increment
1	1	1	Skip

There are two additional control bits, whose use is left to your discretion. They are /SET and /TSEN.

/Set is a synchronous preset that is usually used as a power-on reset; however, it may also be used as a one-bit vector to the last addressable location during normal operation.

/Tsen is the enable for the TRI-STATE™ outputs. This has several possible uses, one of which might be testing the hardware by the method of disabling the outputs, then supplying a test address from an external source.

The sequencer generates ten bits, which are divided into two parts. The least-significant four bits are constructed from a PAL16R4, and control the skip operation. During a skip, the state of the LSB is maintained and the next three bits function as a three-bit binary counter. During an increment, all four

least-significant bits function as a binary counter. Carry out (/CO) is generated during skip when CSA₁ through CSA₃ = 1, and during increment when CSA₀ through CSA₃ = 1. Load (/LD) is also generated by the least-significant part, as a function of COND and TF. (See table below.)

/LD States

TF	Cond	/LD
0	0	0
0	1	1
1	0	1
1	1	0

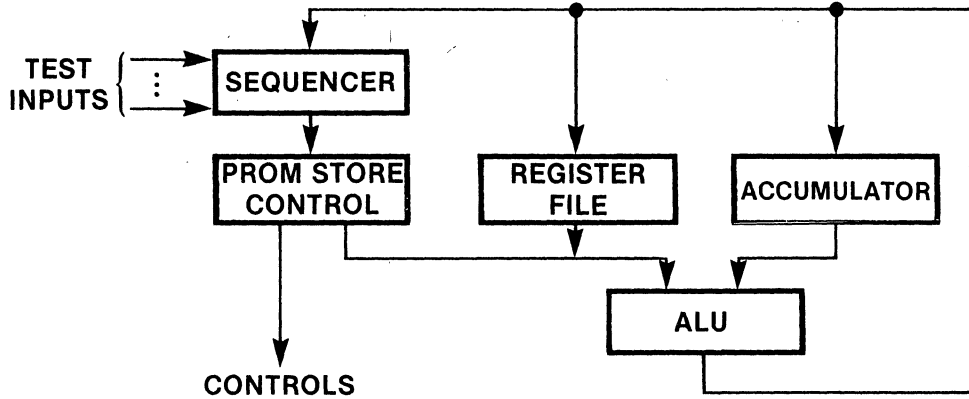
The most-significant six bits are constructed using a PAL16R6, functioning as a six-bit binary counter with carry-in (CI), synchronous load (/LD), and synchronous set (/SET). There is an extra pin that can be used to generate carry-out if you need more than ten bits.

System Integration

One of the first features that is desirable from a system standpoint is the expansion of the COND input to accommodate more than one condition for testing. The can be done nicely by using a 16C1 as a multiplexer. In this scheme, four terms are used as input selects. This leaves 12 terms to be used as condition inputs. This might seem wasteful at first, as 4 select terms could decode 16 inputs. Using the PAL, however, it is only a superficial waste, and the trade-off is the greater design flexibility you have by comparison with a standard multiplexer.

One COND output should be either true or false in order to generate unconditional increments, skips, or branches. The true or false state needs only to be a function of the four select terms, and doesn't require a condition input to be grounded or pulled up. Other functions, such as AND, OR, or XOR, can be performed on the condition inputs internally, too--functions a multiplexer would force you to design in external logic.

The following Figure shows how the sequencer design described here can be integrated into a system that provides subroutine capability. In the figure, the same control-store field is used to generate literals and branch addresses. Subroutines are accomplished by loading the return address into the register file before the subroutine jump is taken and then reading the return address out of the file when the subroutine's return executes.



System Implementation of Sequencer

Control Store Sequencer, Most Significant Stage

Design Specification PAL16R4

PAL16R4 PAL DESIGN SPECIFICATION
 PAT0028
 CONTROL STORE SEQUENCER, LEAST SIGNIFICANT STAGE

CLK NC TF SKIP /SET BA0 BA1 BA2 BA3 GND /TSEN /CO /LD
 CSA3 CSA2 CSA1 CSA0 /ICOND /COND VCC

$$/CSA0 := /SET \cdot /ICOND \cdot CSA0 + /SET \cdot ICOND \cdot SKIP \cdot /CSA0 + /SET \cdot ICOND \cdot /SKIP \cdot BA0$$

$$/CSA1 := /SET \cdot CSA0 \cdot CSA1 \cdot /ICOND + /SET \cdot /ICOND \cdot /CSA0 \cdot CSA1 + /SET \cdot ICOND \cdot SKIP \cdot CSA1 + /SET \cdot ICOND \cdot /SKIP \cdot BA2$$

$$/CSA2 := /SET \cdot /ICOND \cdot CSA0 \cdot CSA1 \cdot CSA2 + /SET \cdot /ICOND \cdot /CSA0 \cdot /CSA2 + /SET \cdot LD \cdot /CSA1 \cdot CSA2 + /SET \cdot /ICOND \cdot SKIP \cdot CSA1 \cdot CSA2 + /SET \cdot ICOND \cdot /SKIP \cdot BA2$$

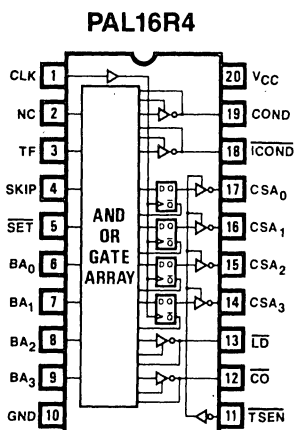
$$/CSA3 := /SET \cdot /ICOND \cdot CSA0 \cdot CSA1 \cdot CSA2 \cdot CSA3 + /SET \cdot /ICOND \cdot /CSA0 \cdot /CSA3 + /SET \cdot LD \cdot /CSA1 \cdot /CSA3 + /SET \cdot LD \cdot CSA2 \cdot CSA3 + /SET \cdot ICOND \cdot SKIP \cdot CSA1 \cdot CSA2 \cdot CSA3 + /SET \cdot ICOND \cdot /SKIP \cdot BA3$$

$$IF (VCC) \quad CO = CSA0 \cdot CSA1 \cdot CSA2 \cdot CSA3 + TF \cdot COND \cdot SKIP \cdot CSA1 \cdot CSA2 \cdot CSA3 + /TF \cdot /COND \cdot SKIP \cdot CSA1 \cdot CSA2 \cdot CSA3$$

$$IF (VCC) \quad ICOND = TF \cdot COND + /TF \cdot /COND$$

$$IF (VCC) \quad LD = TF \cdot COND \cdot /SKIP + /TF \cdot /COND \cdot /SKIP$$

DESCRIPTION: SEE TEXT

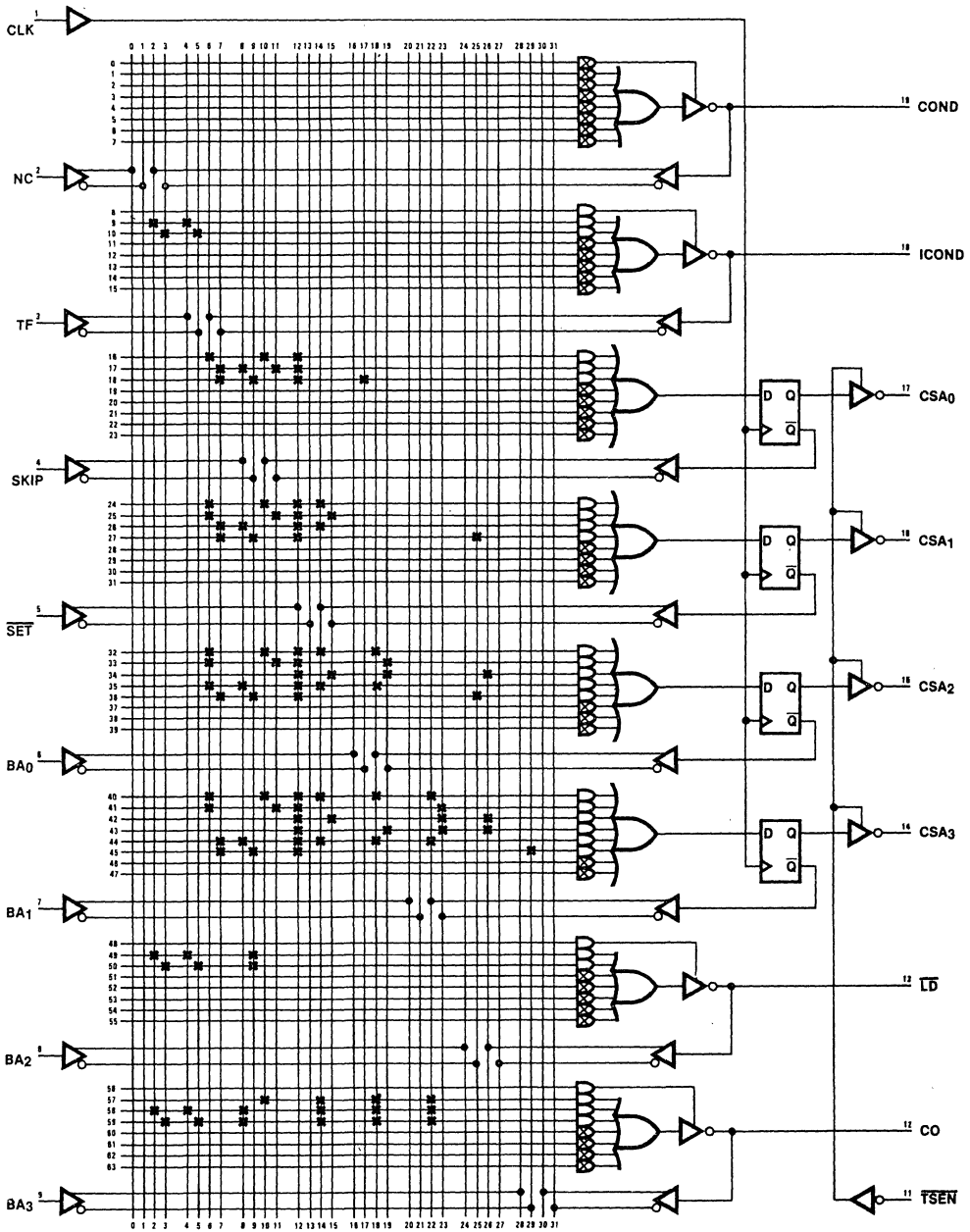


Logic Symbol

Control Store Sequencer, Least Significant Stage, Design Specification.

Control Store Sequencer,
Most Significant Stage

Logic Diagram PAL16R4



Control Store Sequencer, Least Significant State, Logic Diagram.

Control Store Sequencer,
Most Significant Stage

Design Specification PAL16R6

PAL16R6

PAL DESIGN SPECIFICATION

PAT0029

CONTROL STORE SEQUENCER, MOST SIGNIFICANT STAGE

CLK /SET BA4 BA5 BA6 BA7 BA8 BA9 /LD GND /TSEN NC CSA9 CSA8 CSA7 CSA6
CSA5 CSA4 /CI VCC

/CSA4 := /SET*CSA4*CI*/LD + /CSA4*/CI*/LD*/SET + /SET*LD*/BA4

/CSA5 := /SET*CSA4*CSA5*CI*/LD + /SET*/CSA5*/CI*/LD
+ /SET*/CSA4*/CSA5*/LD + /SET*LD*/BA5/CSA6 := /SET*CSA4*CSA5*CSA6*CI*/LD + /SET*/CSA6*/CI*/LD
+ /CSA4*/CSA6*/LD*/SET + /SET*/CSA5*/CSA6*/LD
+ /SET*LD*/BA6/CSA7 := /SET*CSA4*CSA5*CSA6*CSA7*CI*/LD
+ /SET*/CSA7*/CI*/LD + /SET*/CSA4*/CSA7*/LD
+ /SET*/CSA5*/CSA7*/LD + /SET*/CSA6*/CSA7*/LD
+ LD*/BA7*/SET/CSA8 := /SET*CSA4*CSA5*CSA6*CSA7*CSA8*CI*/LD
+ /SET*/CSA8*/CI*/LD + /SET*/CSA4*/CSA8*/LD
+ /SET*/CSA5*/CSA8*/LD + /SET*/CSA6*/CSA8*/LD
+ /SET*/CSA7*/CSA8*/LD + /SET*LD*/BA8/CSA9 := /SET*CSA4*CSA5*CSA6*CSA7*CSA8*CSA9*CI*/LD
+ /SET*/CSA9*/CI*/LD + /SET*/CSA4*/CSA9*/LD
+ /SET*/CSA5*/CSA9*/LD + /SET*/CSA6*/CSA9*/LD
+ /SET*/CSA7*/CSA9*/LD + /SET*/CSA8*/CSA9*/LD
+ /SET*LD*/BA9

DESCRIPTION:

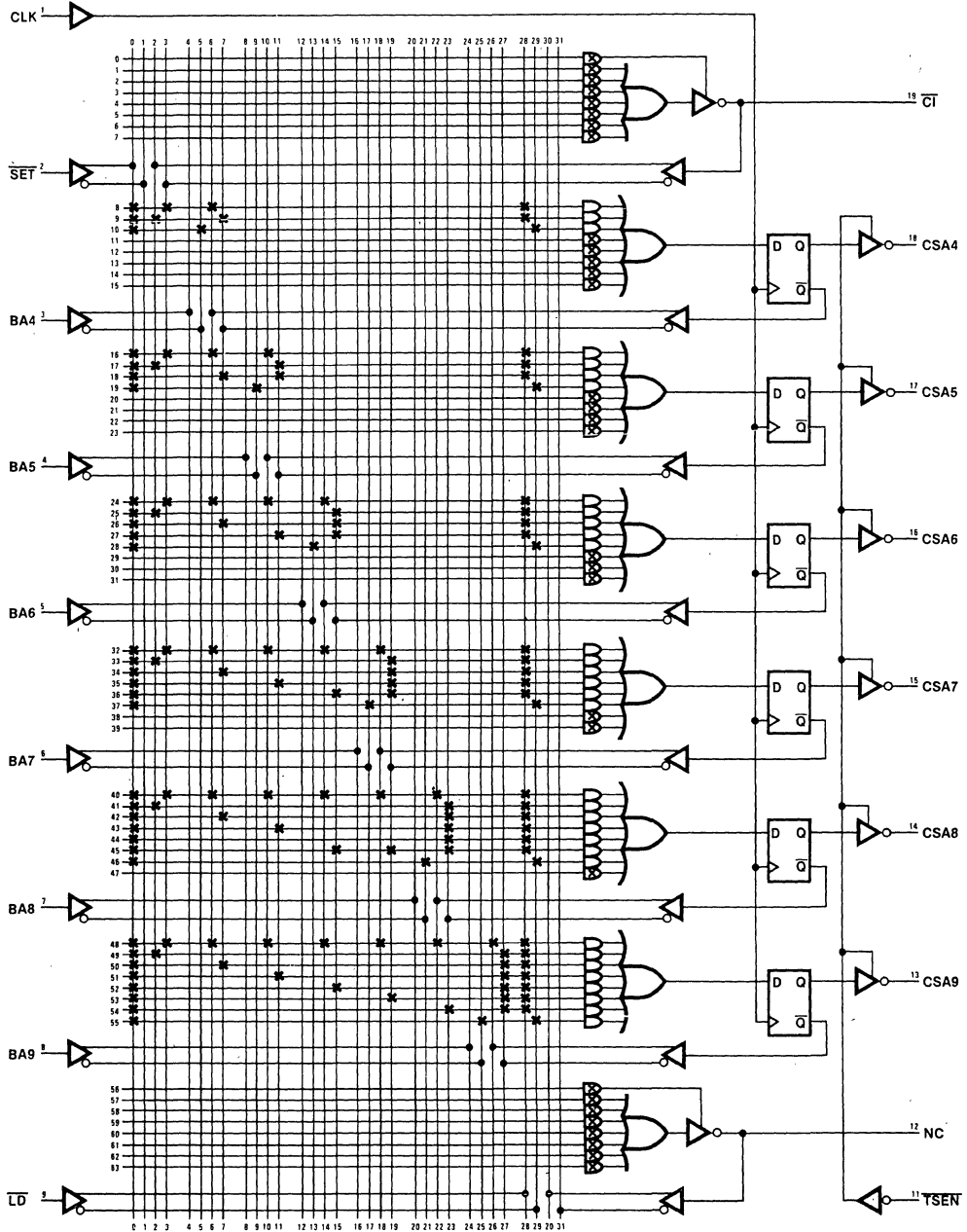
THE 6-BIT COUNTER INCREMENTS WHEN THE /LD LINE IS HIGH
IF CARRY AND /SET. THE OUTPUTS ARE ENABLED WHEN /TSEN IS LOW.

/SET	CI	/LD	CLK	CSA	OPERATION
L	X	X	L-H	ALL HIGH	SET
H	X	L	L-H	BA	LD
H	H	H	L-H	CSA	NOP
H	L	H	L-H	CSA PLUS 1	INCR

Control Store Sequencer, Most Significant Stage, Design Specification.

Control Store Sequencer,
Most Significant Stage

Logic Diagram PAL16R6



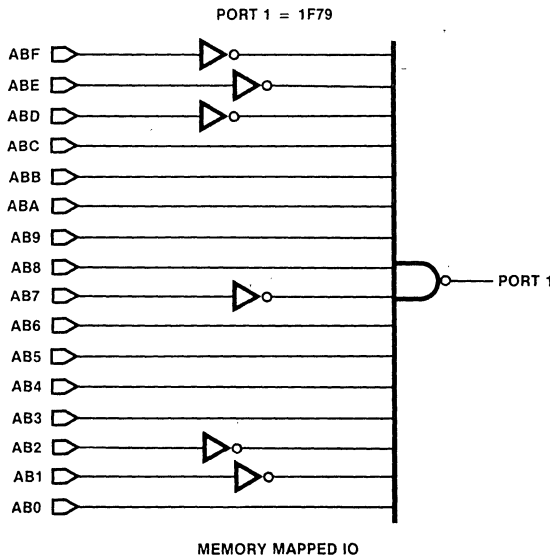
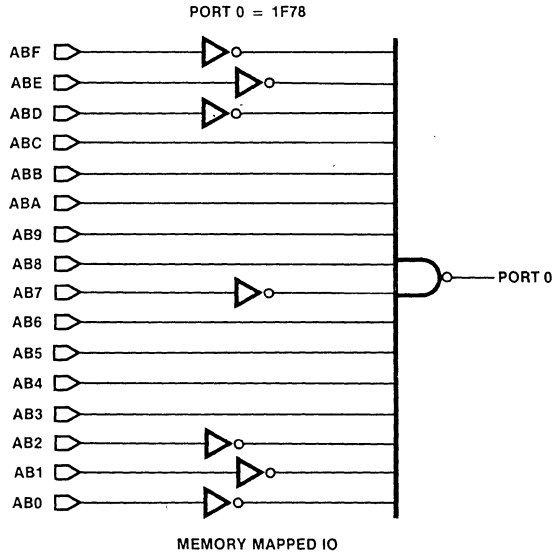
Control Store Sequencer, Most Significant Stage, Logic Diagram.

MEMORY-MAPPED I/O

Memory-mapped I/O is an interface technique that treats I/O devices' physical addresses as undifferentiated from memory address space. That is, no Memory-I/O decoding is required. Furthermore, most computers have more instructions to manipulate the contents of memory than they have I/O instructions. Therefore, the use of memory mapping can make I/O control much more flexible. PALs can be used to make memory-mapped I/O implementation easy, even if changes in memory addresses are required.

Functional Description

The figure below shows a circuit that is typical of those found in memory-mapped I/O applications. The inputs to the decode logic are the system memory address lines, A₀-A_F. The logic shown compares the address on the memory bus with the programmed comparison address. When an address on the bus matches, the corresponding I/O port enable signal is set. In conjunction with other system control signals, this enable can be used to transfer data to and from the system data bus.



Memory-Mapped I/O Logic Diagram

PAL Design

One PAL16L2 can be used to monitor a 16-bit address bus, fully decode addresses, and furnish enables to two ports, each of which could be anywhere within 64K of address space. Partial decoding for a larger number of ports could be done using other members of the PAL family.

Typical logic equations for the memory-mapped I/O logic are as follows:

$$\begin{aligned} \text{Port 0} &= \overline{\text{AB0}} \cdot \overline{\text{AB1}} \cdot \overline{\text{AB2}} \cdot \text{AB3} \cdot \text{AB4} \cdot \\ &\quad \text{AB5} \cdot \text{AB6} \cdot \text{AB7} \cdot \text{AB8} \cdot \text{AB9} \cdot \\ &= \text{ABA} \cdot \text{ABB} \cdot \text{ABC} \cdot \overline{\text{ABD}} \cdot \overline{\text{ABE}} \cdot \overline{\text{ABF}} \cdot \\ &[\text{Note: source data incorrect}] \end{aligned}$$

$$\begin{aligned} \text{Port 1} &= \text{AB0} \cdot \overline{\text{AB1}} \cdot \overline{\text{AB2}} \cdot \text{AB3} \cdot \text{AB4} \cdot \\ &\quad \text{AB5} \cdot \text{AB6} \cdot \overline{\text{AB7}} \cdot \text{AB8} \cdot \text{AB9} \cdot \text{ABA} \\ &\quad \cdot \text{ABB} \cdot \text{ABC} \cdot \overline{\text{ABD}} \cdot \overline{\text{ABE}} \cdot \\ &\quad \overline{\text{ABF}} \cdot \end{aligned}$$

The above example shows address decoding for memory locations 1F78_H and 1F79_H. The equation terms could be changed to accommodate any 16-bit address.

Memory Mapped I/O**Design Specification PAL16L2**

PAL16L2
PAT0008
MEMORY MAPPED I/O

PAL DESIGN SPECIFICATION

AB0 AB1 AB2 AB3 AB4 AB5 AB6 AB7 AB8 GND AB9 AB8 ABE ABC
 $\overline{\text{PORT1}}$ $\overline{\text{PORT0}}$ AED ABE ABF VCC

PORT0 = $\overline{\text{AB0}} \cdot \overline{\text{AB1}} \cdot \overline{\text{AB2}} \cdot \text{AB3} \cdot \text{AB4} \cdot \text{AB5} \cdot \text{AB6} \cdot \overline{\text{AB7}} \cdot \overline{\text{AB8}} \cdot \overline{\text{AB9}} \cdot \overline{\text{ABE}} \cdot \overline{\text{ABC}} \cdot$
 $\overline{\text{AED}} \cdot \overline{\text{ABE}} \cdot \overline{\text{ABF}}$

PORT1 = $\text{AB0} \cdot \overline{\text{AB1}} \cdot \overline{\text{AB2}} \cdot \text{AB3} \cdot \text{AB4} \cdot \text{AB5} \cdot \text{AB6} \cdot \overline{\text{AB7}} \cdot \overline{\text{AB8}} \cdot \overline{\text{AB9}} \cdot \overline{\text{ABE}} \cdot \overline{\text{ABC}} \cdot$
 $\overline{\text{AED}} \cdot \overline{\text{ABE}} \cdot \overline{\text{ABF}}$

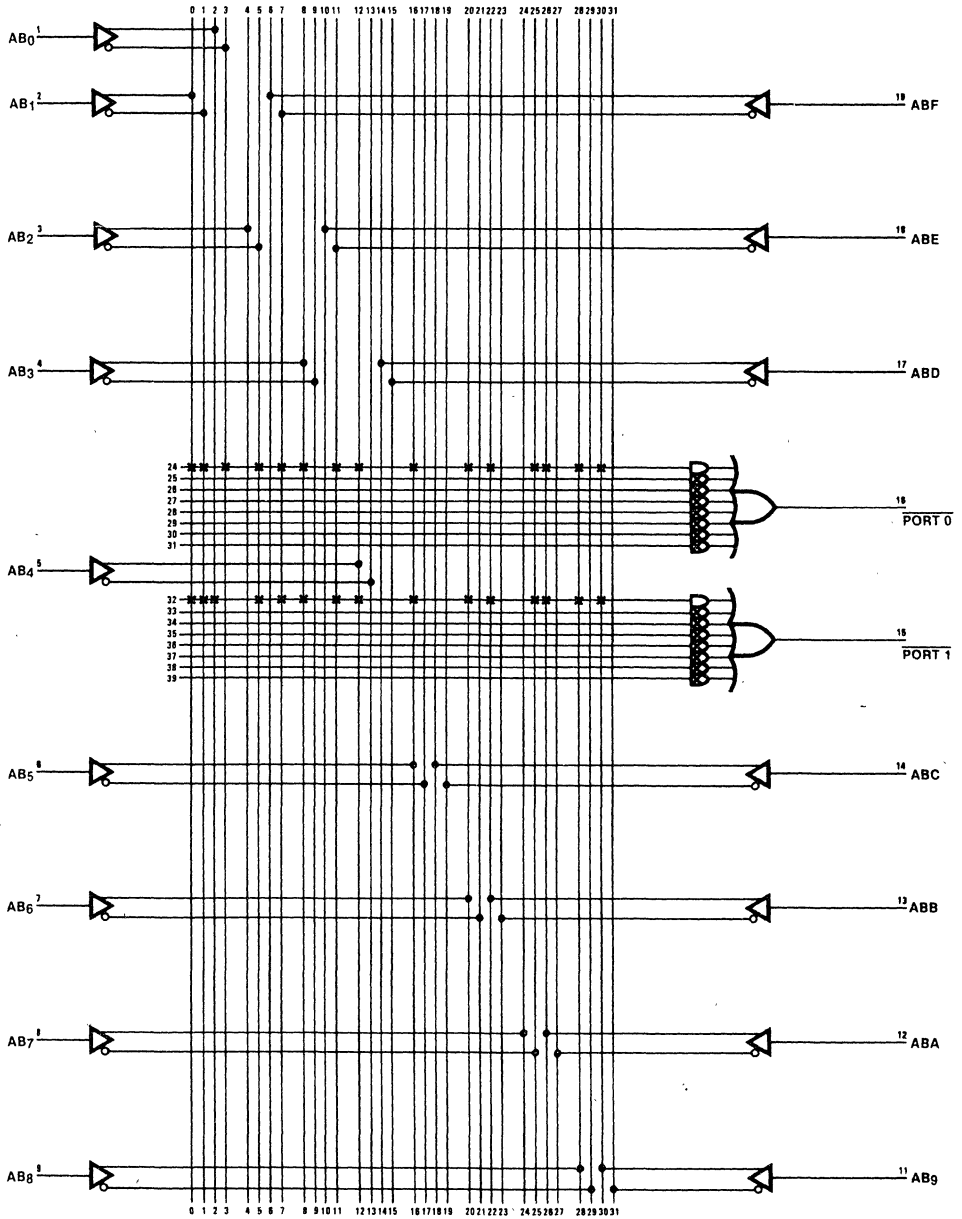
DESCRIPTION:

THE PAL DECODES THE SPECIFIED MEMORY ADDRESS WORD TO PRODUCE A PORT ENABLE FOR PORT0 AND PORT1 AS FOLLOWS:

PAL16L2 Memory-mapped I/O Decoder Design Specification.

Memory Mapped I/O

Logic Diagram PAL16L2

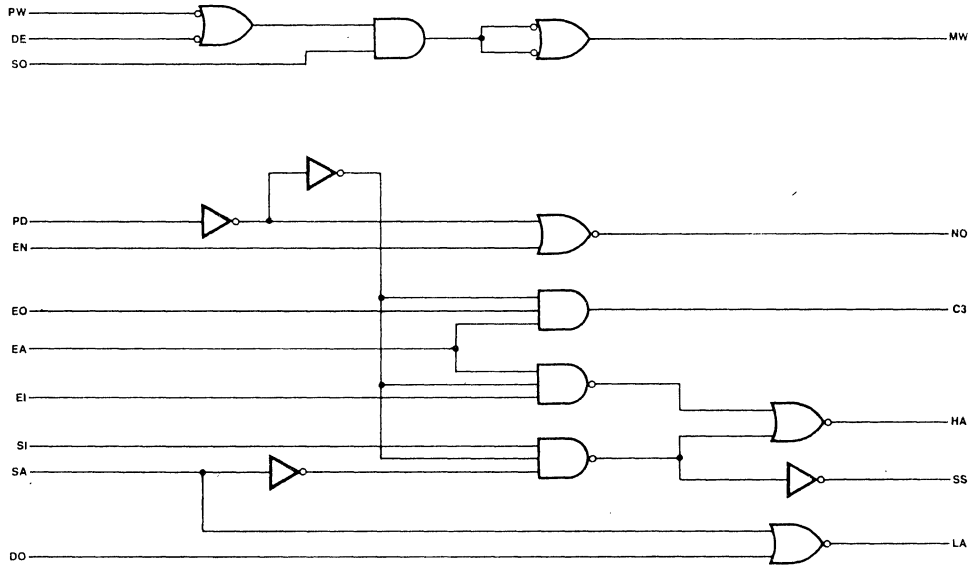


PAL16L2 Memory-mapped I/O Decoder Logic Diagram.

CONTROL LOGIC FOR 8080 CPU BOARD

The 8080 is one of the most widely-used of all current microprocessor designs. However, using it in a system requires that you decode and supply a fairly complex set of control signals.

With the rapid decline in 8080 prices, the logic required to perform this control decoding has become more expensive than the 8080 itself. This application note shows how a PAL can be used to eliminate much of this costly support logic on an 8080 CPU board.



PAL16L8 Control Logic for 8080 CPU Board, Combinatorial Logic Diagram.

DESCRIPTION:
PORTION OF LOGIC FROM 8080 CPU BOARD

PAL16L8 PAL DESIGN SPECIFICATION
PAT0012
PORTION OF RANDOM CONTROL LOGIC FOR 8080 CPU BOARD

PD EN EO EA SI SA EI DO DE GND SO NO C3 HA SS LA MW PW NC3 VCC

IF (VCC) <MMW= SO♦/PW + SO♦/DE

IF (VCC) <LA= SA + DO

IF (VCC) <SS= /SI + /PD + EA

IF (VCC) <HA= /SI + /PD + SA + /EA + /EI

IF (VCC) <C3= /PD + /EO + /EA

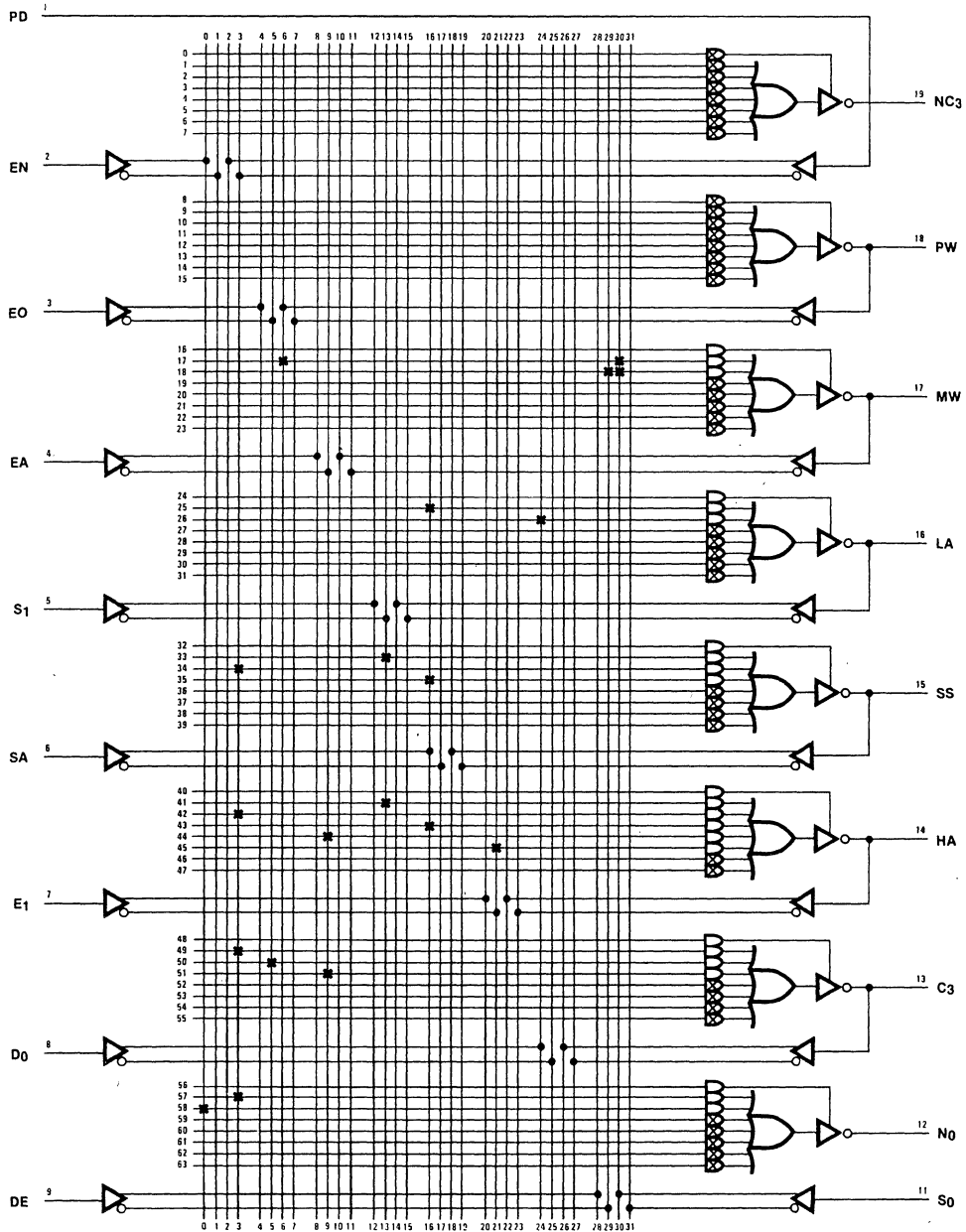
IF (VCC) <NO= /PD + EN

PAL16L8 Control Logic for 8080 CPU Board, Design Specification.

Portion of Random Control Logic for
8080 CPU Board

Logic Diagram PAL16L8

Application Suggestions



PAL16L8 Control Logic for 8080 CPU Board, Coded PAL Logic Diagram.

Portion of Random Control Logic for 8080 CPU Board (Improved Design)

Design Specification PAL12H6

PAL12H6
PAT0013

PAL DESIGN SPECIFICATION

PORTION OF RANDOM CONTROL LOGIC FOR 8080 CPU BOARD

PI EN ED EA S1 SA E1 DO DE GND SO NO3 NO C3 HA SS LA MW PM VCC

$$MW = \neg SO + PM \cdot DE$$

$$LA = \neg SA \cdot \neg DO$$

$$C3 = S1 \cdot PI \cdot \neg SA$$

$$HA = S1 \cdot PI \cdot \neg SA \cdot EA \cdot E1$$

$$C3 = PI \cdot ED \cdot EA$$

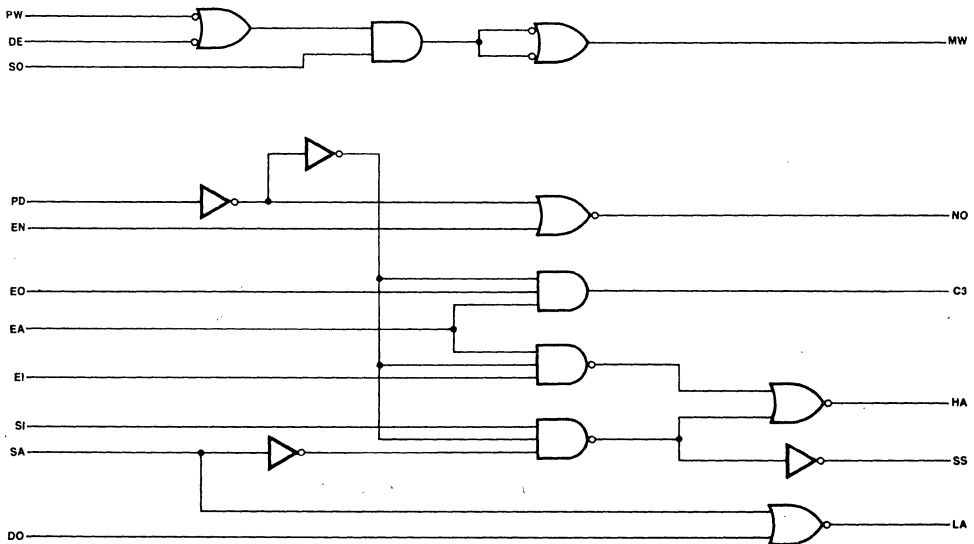
$$NO = PI \cdot \neg EN$$

DESCRIPTION:

PORTION OF LOGIC FROM 8080 CPU BOARD

NOTE: THIS DESIGN IS IMPROVED OVER THE PREVIOUS EXAMPLE AS WE WERE ABLE TO IMPLEMENT THE SAME EQUATIONS IN A SMALLER PAL. THIS WAS ACCOMPLISHED BY INVERTING THE EQUATIONS, THUS, REDUCING THE NUMBER OF PRODUCTS PER OUTPUT TO A MAXIMUM OF TWO.

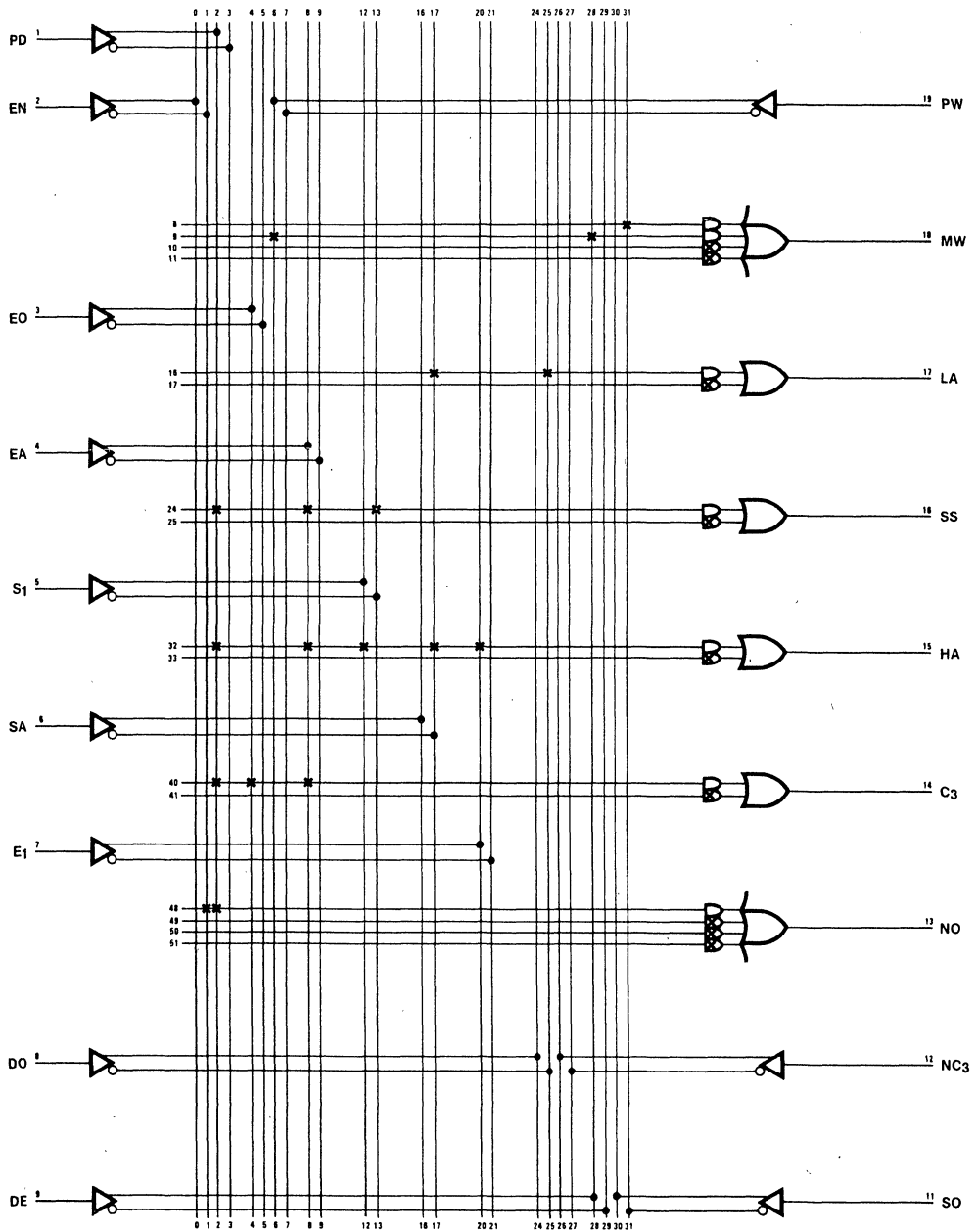
PAL12H6 Control Logic for 8080 CPU Board, Design Specification.



PAL12H6 Control Logic for 8080 CPU Board, Combinatorial Logic Diagram.

Portion of Random Control Logic for 8080 CPU Board (Improved Design)

Logic Diagram PAL12H6



PAL12H6 Control Logic for 8080 CPU Board, Coded PAL Logic Diagram.

HEXADECIMAL DECODER/LAMP DRIVER

The increasing use of microcomputers has led to an increased need to display numbers in hexadecimal format (0-9, A-F). Standard drivers for this function are not available, so most applications are forced to use several packages to decode each digit of the display. Since 6 to 12 digits are often being displayed, this approach can become very expensive. This example demonstrates how the hexadecimal display format can be both decoded and the LED indicators driven using a single PAL for each digit of the display.

Functional Description

A hex decoder/lamp driver accepts a four-bit hex digit, converts it to its corresponding seven-segment display code, and activates the appropriate segments on the display. These drivers can be used in both direct-drive and multiplexed display applications. A single PAL can provide both the basic decode/drive functions, and additional useful features as well.

Circuit Description

The figure shows three digits of a display system that uses three PALs to implement the complete decoding and display-driving functions. The inputs to each section are a hex code on pins D₀-D₃, a ripple blanking signal, an intensity control signal, and a lamp test signal.

The hex codes are decoded to form the seven-segment patterns shown in the figure. The input codes, digit, represented, and segments driven are as follows:

D ₃	D ₂	D ₁	D ₀	Digit	Segments
0	0	0	0	0	ABCDEF
0	0	0	1	1	BC
0	0	1	0	2	ABDEG
0	0	1	1	3	ABCDG
0	1	0	0	4	BCFG
0	1	0	1	5	ACDF
0	1	1	0	6	ACDEF
0	1	1	1	7	ABC
1	0	0	0	8	ABCDEFG
1	0	0	1	9	ABCFG
1	0	1	0	A	ABCEFG
1	0	1	1	B	CDEFG
1	1	0	0	C	ADEF
1	1	0	1	D	BCDEG
1	1	1	0	E	ADEFG
1	1	1	1	F	AEFG

Ripple-blanking input RBI is used to suppress leading zeroes in the display. The signal is propagated from the most significant digit to the least significant digit. If the digit input is zero and RBI is low (indicating that the previous digit is also zero), all segments are left blank and this digit position's ripple-blanking output RBO is set low.

Intensity control signal IC controls the duty cycle of the display driver. When IC is high, all segment drivers are turned off. Pulsing this pin with a duty-cycled signal allows the adjustment of the display's apparent brightness.

Lamp test signal LT lets you check to see if all LED segments are energized.

PAL Implementation

The PAL16L8 has both the required I/O pins and the drive current capability to perform as the complete display decoder-driver circuit with seven inputs and eight outputs. The logic equations for this circuits are shown in the listing. One PAL drives each digit; they may be cascaded without limit. With minor changes, the same logical structure could be used with multiplexer logic to allow a single PAL to decode and drive multiple digits.

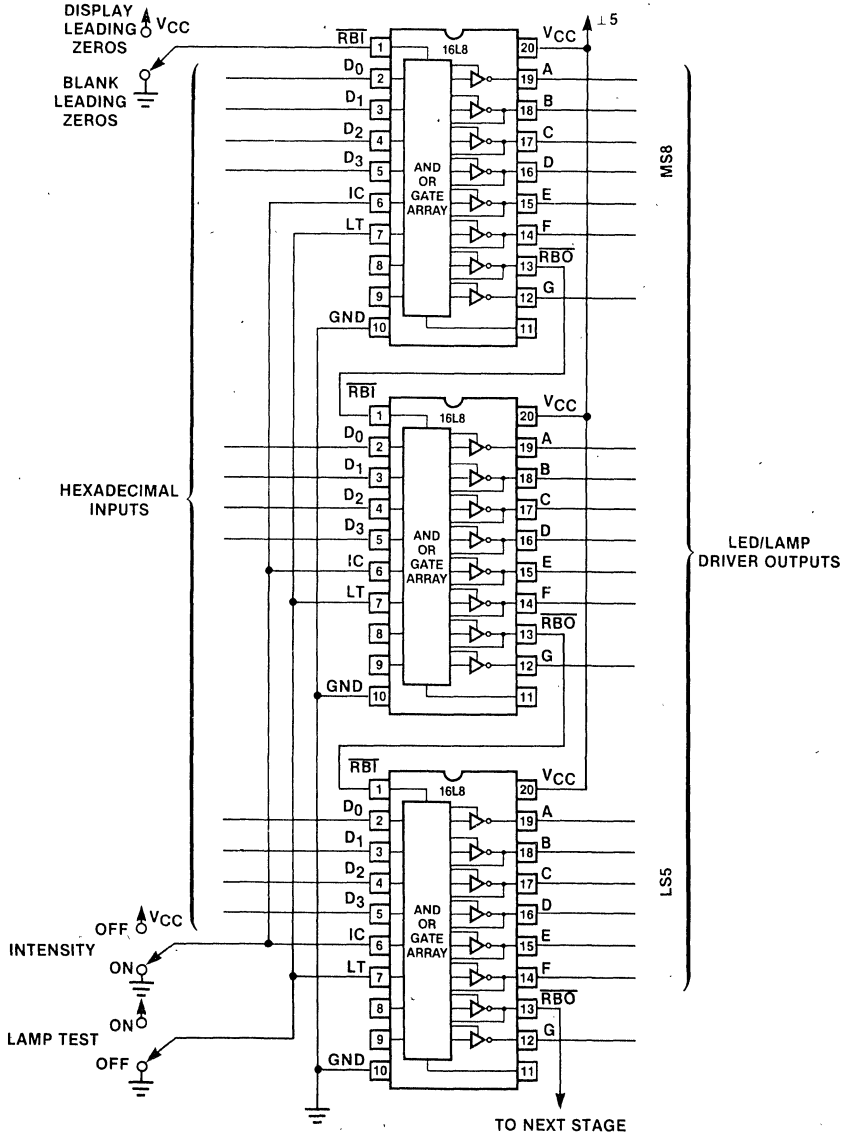
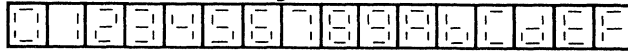
Hex Decoder/7 Seg. Driver w/Ripple Blanking, Intensity Con., & Lamp Test

Logic Schematic

THREE STAGE HEXADECIMAL DECODER / DRIVER

A			
F	G	B	
E		C	
			D

 PAL16L8
 BCD TO HEXADECIMAL
 DECODER/7SEGMENT
 DRIVER WITH RIPPLE BLANKING



Hex Display Decoder-Driver, Combinatorial Logic Diagram.

Hex Decoder/7 Seg. Drive w/Ripple Blanking, Intensity Con., & Lamp Test

Design Specification PAL16L8

PAL16L8 PAL DESIGN SPECIFICATION
 PAT0007
 HEX DECODER/7SEG. DRIVER W/RIPPLE BLANKING, INTENSITY CON., & LAMP TEST
 /RBI D0 D1 D2 D3 IC LT NC NC GND NC G /RBD F E D C B A VCC

$$\begin{aligned} \text{IF } \langle \text{IC} \rangle \text{ /A} &= \text{/RBD} \cdot \text{/D0} \cdot \text{/D2} + \text{/RBD} \cdot \text{/D0} \cdot \text{D3} + \text{/RBD} \cdot \text{D1} \cdot \text{D2} + \\ &\text{/RBD} \cdot \text{D1} \cdot \text{D2} \cdot \text{/D3} + \text{/RBD} \cdot \text{D0} \cdot \text{D2} \cdot \text{/D3} + \text{/RBD} \cdot \text{D1} \cdot \text{/D2} \cdot \text{D3} + \text{LT} \\ \text{IF } \langle \text{IC} \rangle \text{ /B} &= \text{/RBD} \cdot \text{D2} \cdot \text{/D3} + \text{/RBD} \cdot \text{/D0} \cdot \text{/D2} + \text{/RBD} \cdot \text{/D0} \cdot \text{D1} \cdot \text{/D3} + \\ &\text{/RBD} \cdot \text{D0} \cdot \text{D1} \cdot \text{/D3} + \text{/RBD} \cdot \text{D0} \cdot \text{/D1} \cdot \text{D3} + \text{LT} \\ \text{IF } \langle \text{IC} \rangle \text{ /C} &= \text{/RBD} \cdot \text{D0} \cdot \text{/D1} + \text{/RBD} \cdot \text{D0} \cdot \text{/D2} + \text{/RBD} \cdot \text{/D1} \cdot \text{/D2} + \\ &\text{/RBD} \cdot \text{D2} \cdot \text{/D3} + \text{/RBD} \cdot \text{/D2} \cdot \text{D3} + \text{LT} \\ \text{IF } \langle \text{IC} \rangle \text{ /D} &= \text{/RBD} \cdot \text{/D1} \cdot \text{D3} + \text{/RBD} \cdot \text{/D0} \cdot \text{/D2} \cdot \text{/D3} + \\ &\text{/RBD} \cdot \text{D0} \cdot \text{D1} \cdot \text{/D2} + \text{/RBD} \cdot \text{/D0} \cdot \text{D1} \cdot \text{D2} + \text{/RBD} \cdot \text{D0} \cdot \text{/D1} \cdot \text{D2} + \text{LT} \\ \text{IF } \langle \text{IC} \rangle \text{ /E} &= \text{/RBD} \cdot \text{/D0} \cdot \text{/D2} + \text{/RBD} \cdot \text{D2} \cdot \text{D3} + \text{/RBD} \cdot \text{/D0} \cdot \text{D1} + \\ &\text{/RBD} \cdot \text{D1} \cdot \text{D3} + \text{LT} \\ \text{IF } \langle \text{IC} \rangle \text{ /F} &= \text{/RBD} \cdot \text{/D0} \cdot \text{/D1} + \text{/RBD} \cdot \text{/D2} \cdot \text{D3} + \text{/RBD} \cdot \text{D1} \cdot \text{D3} + \\ &\text{/RBD} \cdot \text{/D0} \cdot \text{D2} + \text{/RBD} \cdot \text{/D1} \cdot \text{D2} \cdot \text{/D3} + \text{LT} \\ \text{IF } \langle \text{VCC} \rangle \text{ /RBD} &= \text{/D0} \cdot \text{/D1} \cdot \text{/D2} \cdot \text{/D3} \cdot \text{/RBI} \\ \text{IF } \langle \text{IC} \rangle \text{ /G} &= \text{/RBD} \cdot \text{D1} \cdot \text{/D2} + \text{/RBD} \cdot \text{D0} \cdot \text{D3} + \text{/RBD} \cdot \text{/D2} \cdot \text{D3} + \\ &\text{/RBD} \cdot \text{/D0} \cdot \text{D1} + \text{/RBD} \cdot \text{/D1} \cdot \text{D2} \cdot \text{/D3} + \text{LT} \end{aligned}$$

DESCRIPTION:
 THE HEXDECIMAL DECODER/7-SEGMENT DRIVER FEATURES ACTIVE LOW OUTPUTS FOR DRIVING DISPLAY DIRECTLY.

IF DATA INPUT IS ZERO AND RIPPLE BLANKING INPUT (RBI) IS LOW THAT DIGIT WILL BE BLANKED AND RIPPLE BLANKING OUTPUT WILL BE LOW.

THE RIPPLE BLANKING OUTPUT (RBD) PROVIDES BLANKING INFORMATION FOR THE NEXT LEAST SIGNIFICANT STAGE. IT PROVIDES A LOW IF /RBI IS LOW AND THE DATA IN IS ZERO.

WHEN HIGH THE INTENSITY CONTROL (IC) WILL TURN OFF THE ENTIRE DISPLAY. IC MAY BE PULSED TO VARY THE INTENSITY OF THE DISPLAY.

WHEN HIGH THE LAMP TEST INPUT (LT) WILL TURN ON THE DISPLAY.

		INPUTS					OUTPUTS							
LT	IC	/RBI	D0	D1	D2	D3	A	B	C	D	E	F	G	/RBD
L	H	X	X	X	X	X	Z	Z	Z	Z	Z	Z	Z	X
L	L	H	L	L	L	L	L	L	L	L	L	L	H	L
L	L	L	L	L	L	L	H	H	H	H	H	H	L	L
H	L	X	X	X	X	X	L	L	L	L	L	L	L	X

Hex Display Decoder-Driver, Design Specification.

Hex Decoder/7 Seg. Driver
w/Ripple Blanking, Intensity
Con., & Lamp Test

Fuse Pattern PAL16L8

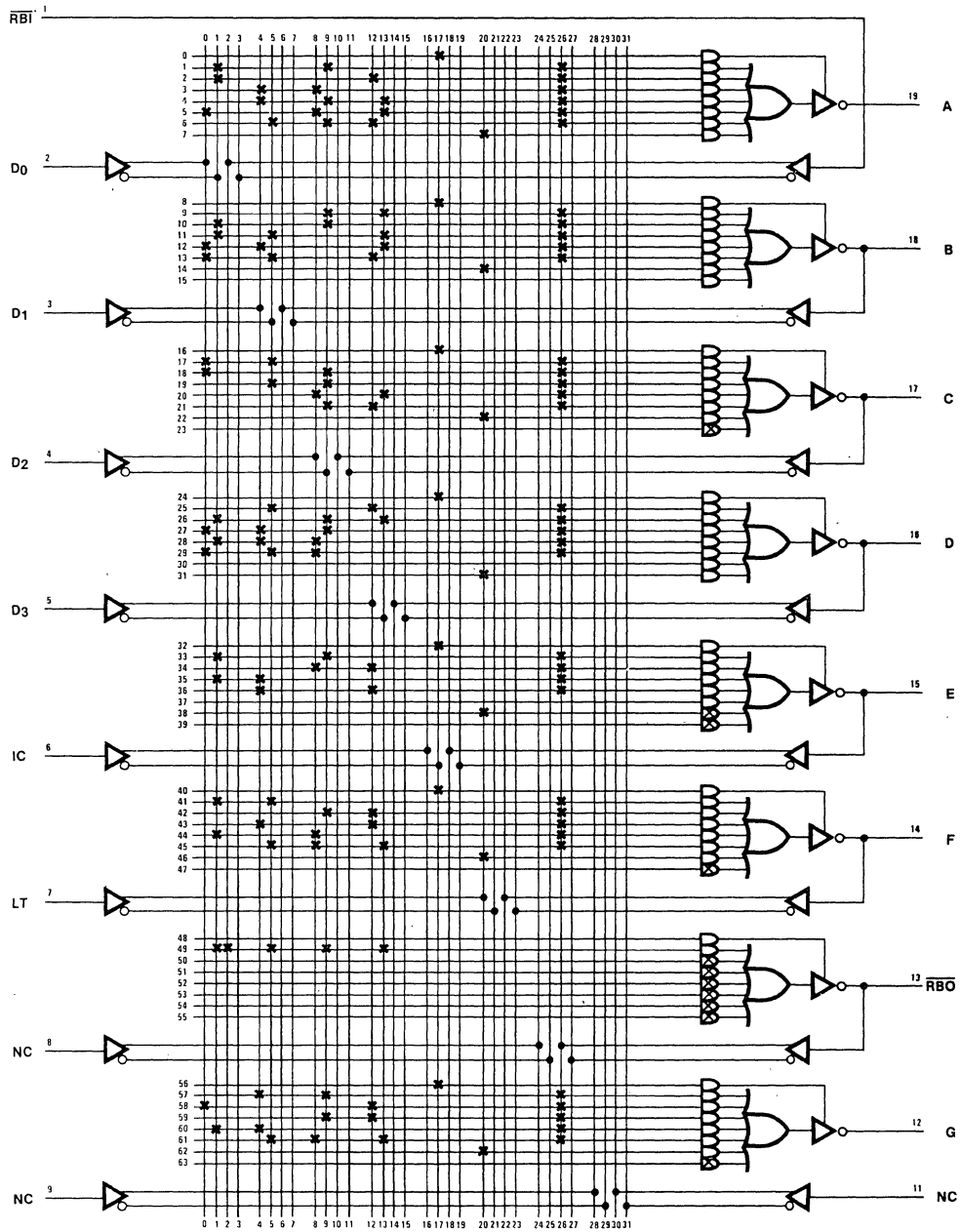
---	---	---	---	---	---	---	---	---	<IC
X	---	X	---	---	---	X	---	---	<FEO♦♦D0♦♦D2
X	---	X	---	---	---	X	---	---	<FEO♦♦D0♦♦D3
X	X	X	---	---	---	X	---	---	<FEO♦♦D1♦♦D2
X	---	X	X	---	---	X	---	---	<FEO♦♦D1♦♦D2♦♦D3
X	---	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D2♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D1♦♦D2♦♦D3
---	---	---	---	X	---	---	---	---	LT
---	---	---	---	X	---	---	---	---	<IC
X	---	X	---	---	---	X	---	---	<FEO♦♦D2♦♦D3
X	---	X	---	---	---	X	---	---	<FEO♦♦D0♦♦D2
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1♦♦D2
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1♦♦D3
---	---	---	---	X	---	---	---	---	LT
---	---	---	---	X	---	---	---	---	<IC
X	---	X	---	---	---	X	---	---	<FEO♦♦D0♦♦D1
X	---	X	---	---	---	X	---	---	<FEO♦♦D0♦♦D2
X	X	X	X	---	---	X	---	---	<FEO♦♦D1♦♦D2
X	X	X	X	---	---	X	---	---	<FEO♦♦D2♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D2♦♦D3
---	---	---	---	X	---	---	---	---	LT
---	---	---	---	X	---	---	---	---	<IC
X	---	X	---	---	---	X	---	---	<FEO♦♦D1♦♦D3
X	---	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D2♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1♦♦D2
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1♦♦D2
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1♦♦D2
---	---	---	---	X	---	---	---	---	LT
---	---	---	---	X	---	---	---	---	<IC
X	---	X	---	---	---	X	---	---	<FEO♦♦D0♦♦D2
X	---	X	---	---	---	X	---	---	<FEO♦♦D2♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1
X	X	X	X	---	---	X	---	---	<FEO♦♦D1♦♦D3
---	---	---	---	X	---	---	---	---	LT
---	---	---	---	X	---	---	---	---	<IC
X	X	X	X	X	X	X	X	X	<D0♦♦D1♦♦D2♦♦D3♦♦PEI
X	X	X	X	X	X	X	X	X	
X	X	X	X	X	X	X	X	X	
X	X	X	X	X	X	X	X	X	
X	X	X	X	X	X	X	X	X	
X	X	X	X	X	X	X	X	X	
---	---	---	---	X	---	---	---	---	<IC
X	---	X	---	---	---	X	---	---	<FEO♦♦D1♦♦D2
X	---	X	---	---	---	X	---	---	<FEO♦♦D0♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D2♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1
X	X	X	X	---	---	X	---	---	<FEO♦♦D1♦♦D2♦♦D3
---	---	---	---	X	---	---	---	---	LT
---	---	---	---	X	---	---	---	---	<IC
X	---	X	---	---	---	X	---	---	<FEO♦♦D1♦♦D2
X	---	X	---	---	---	X	---	---	<FEO♦♦D0♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D2♦♦D3
X	X	X	X	---	---	X	---	---	<FEO♦♦D0♦♦D1
X	X	X	X	---	---	X	---	---	<FEO♦♦D1♦♦D2♦♦D3
---	---	---	---	X	---	---	---	---	LT

Hex Display Decoder-Driver, Fuse Return

Hex Decoder/7 Seg. Driver w/Ripple Blanking, Intensity Con., & Lamp Test

Logic Diagram PAL16L8

Application Suggestions



Hex Display Decoder-Driver, Coded PAL Logic Diagram.

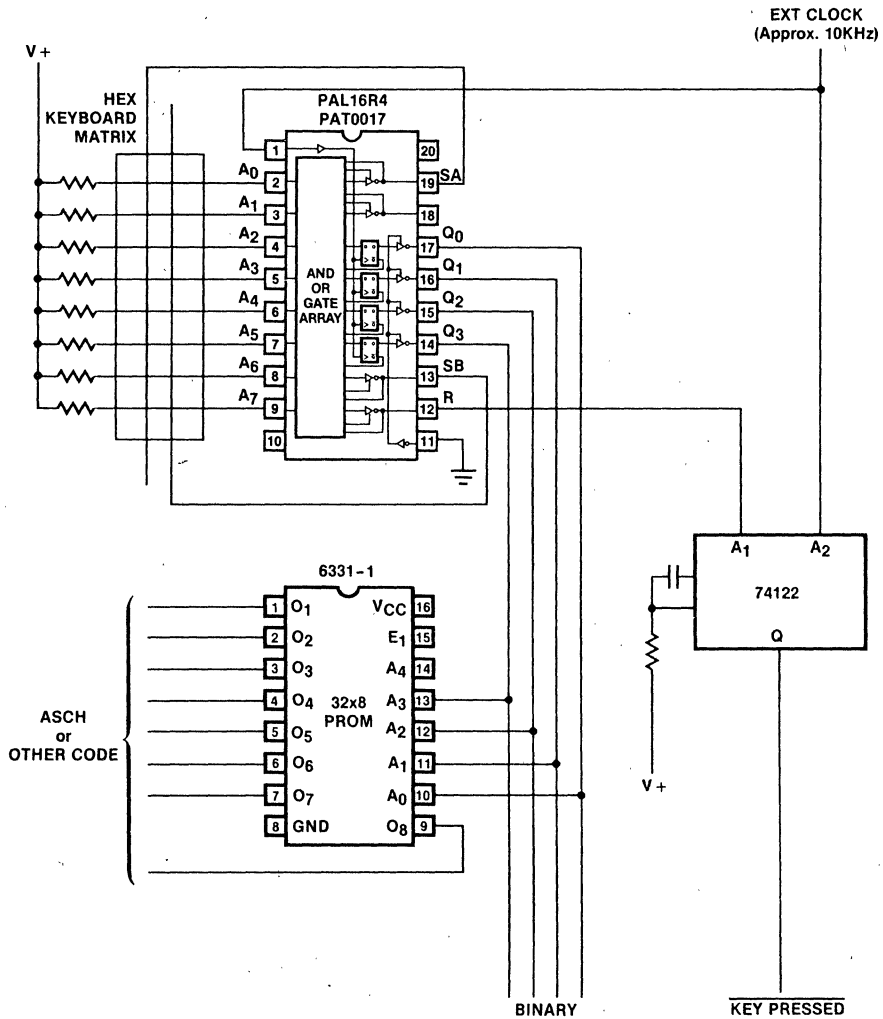
HEXADECIMAL KEYBOARD SCANNER

The popularity of pocket calculators and home computers has created a large market for low-cost keyboards. The logic required to scan small keyboards is typically implemented either in SSI/MSI logic or in a computer-generated software scan. In the first case, the

logic may be rather expensive; in the second case, if the microcomputer system is a busy one, the software scan may be unacceptably slow. A single PAL and just a few inexpensive parts can do the task.

Hex Keyboard Scanner

Logic Diagram PAL16L8



Hex Keyboard Scanner, Combinatorial Logic Diagram.

PAL16R4
 PAT0017
 HEX KEYBOARD SCANNER

PAL DESIGN SPECIFICATION

CLK A0 A1 A2 A3 A4 A5 A6 A7 GND VEH R SB Q3 Q2 Q1 Q0 NC SA VCC

IF (VCC) /SA = /Q3

IF (VCC) /NC = /A0+/Q0+/Q1+/Q2 + /A1+/Q0+/Q1+/Q2 +
 /A2+/Q0+/Q1+/Q2 + /A3+/Q0+/Q1+/Q2 +
 /A4+/Q0+/Q1+/Q2 + /A5+/Q0+/Q1+/Q2 +
 /A6+/Q0+/Q1+/Q2

Q0 := Q0+R + /Q0+/R

Q1 := Q0+Q1+R + /Q0+/Q1+R + /Q1+/R

Q2 := Q0+Q1+Q2+R+/Q0+/Q2+R + /Q1+/Q2+R + /Q2+/R

Q3 := Q0+Q1+Q2+Q3+R + /Q0+/Q3+R + /Q1+/Q3+R + /Q2+/Q3+R + /Q3+/R

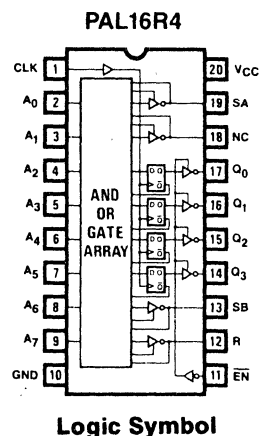
IF (VCC) /SB = Q3

IF (VCC) /R = /NC + /A7+/Q0+/Q1+/Q2

DESCRIPTION:

THE KEYBOARD SCANNER WILL SCAN A 16 KEY KEYBOARD ARRANGED IN A 2X8 MATRIX. THE SCANNER WORKS BY SELECTING ONE ROW OF 8 SWITCHES AND THEN SCANNING THE 8 INPUTS. A LOW ON ANY INPUT WILL DISABLE THE CLOCK GOING INTO THE ONE-SHOT. THE ONE-SHOT IS USED AS A DELAY TO ALLOW THE SWITCH BOUNCE TO SETTLE OUT. AT THE END OF THE TIME DELAY (10MS), KEYPRESSED WILL GO LOW. THE OUTPUTS WILL THEN GIVE THE BINARY CODE FOR THE SWITCH SELECTED. WHEN THE SWITCH IS RELEASED, KEYPRESSED WILL GO HIGH, AND SCANNING WILL CONTINUE. WHEN THE END OF THE ROW IS REACHED, THE SCANNER SWITCHES TO THE OTHER ROW AND CONTINUES SCANNING.

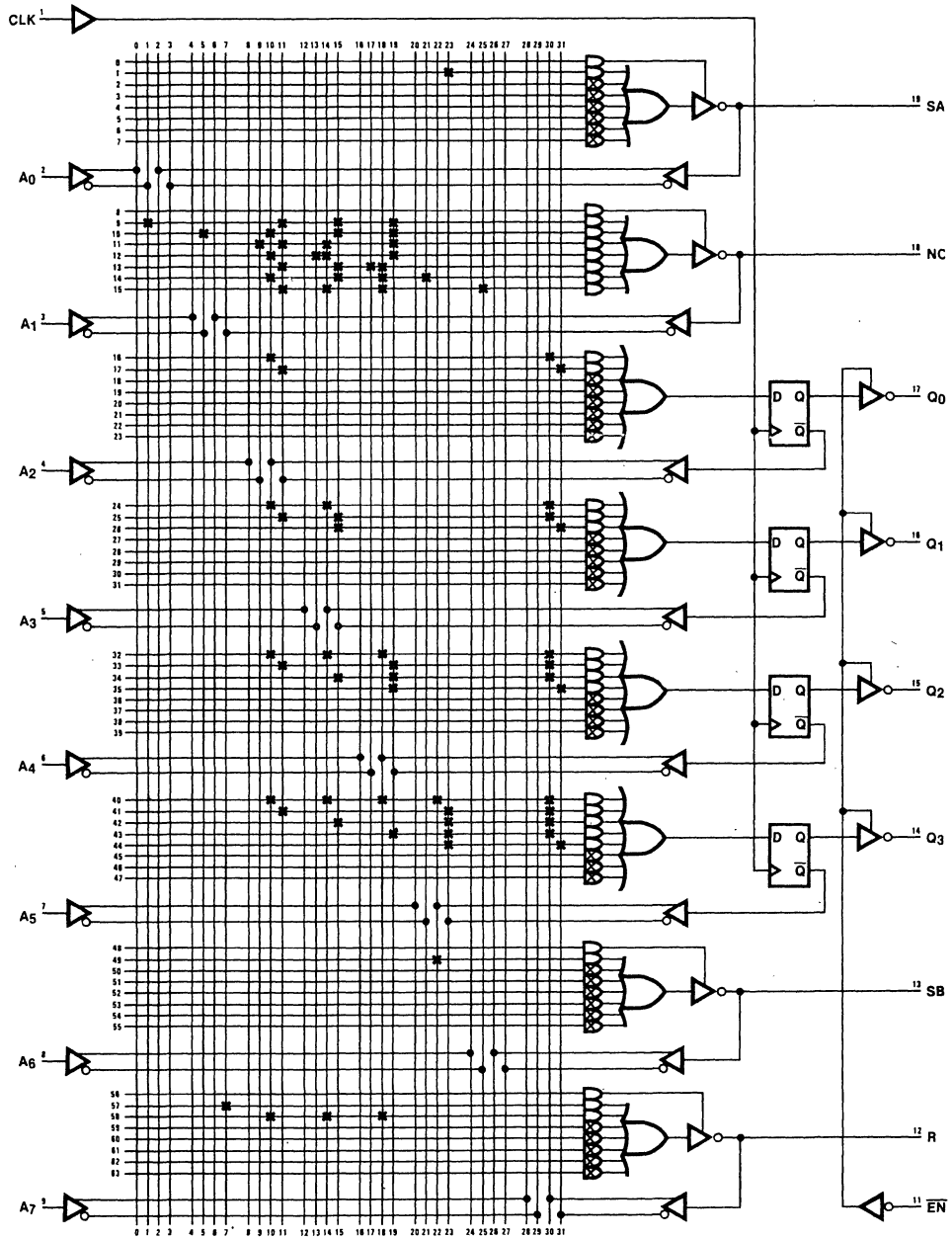
THE EXTERNAL CLOCK SHOULD RUN IN THE RANGE OF 10 KHZ.
 IF ASCII OR OTHER CODED CHARACTERS ARE DESIRED, THE BINARY CAN BE CONVERTED USING A PROM.



Hex Keyboard Scanner

Logic Diagram PAL16R4

Application Suggestions

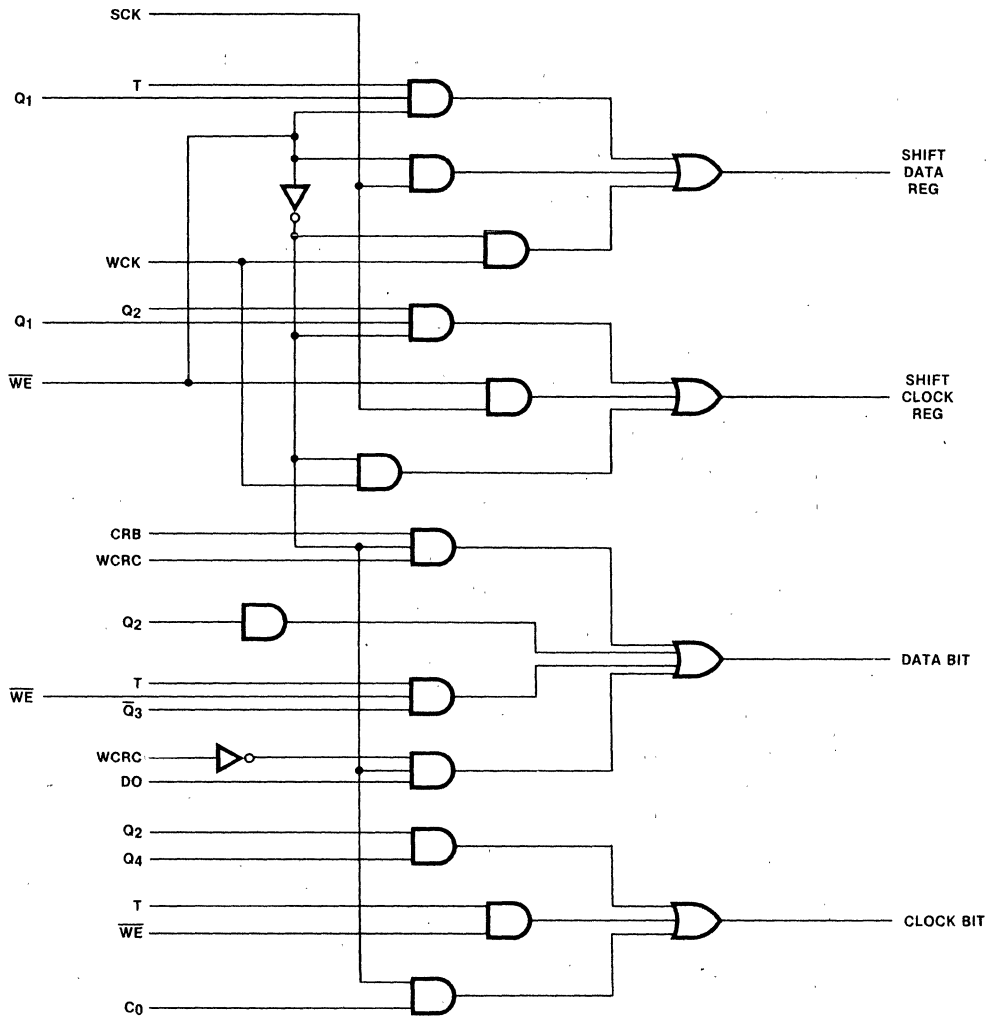


Hex Keyboard Scanner, Coded PAL Logic Diagram.

MINIDISKETTE CONTROL LOGIC

The flexible diskette (floppy), and its smaller brother, the minidiskette, are very popular as mass storage on small systems. Most of these small systems are destined for high-volume applications, so all possible production

economies should be explored. The disk controller is the most complicated (and expensive) part of the disk subsystem; this example shows how a PAL can reduce the size and cost of the controller for a minidiskette-drive controller.



Minidiskette Control Logic Diagram.

Portion of Micro Floppy Control Logic

Design Specification PAL14H4

PAL14H4
PAT0024

PAL DESIGN SPECIFICATION

PORTION OF MICRO FLOPPY CONTROL LOGIC

SCK T 01 MCK 02 /ME CRB MCRC /03 GND 04 CD DD CPB DATBT SCREG SDREG M2 M1 M0C

$$SDREG = T \cdot 01 \cdot /ME + SCK \cdot /ME + ME \cdot MCK$$

$$SCREG = 02 \cdot 01 \cdot ME + SCK \cdot /ME + ME \cdot MCK$$

$$DATBT = CRB \cdot ME \cdot MCRC + 02 + T \cdot /ME \cdot /03 + /MCRC \cdot ME \cdot DD$$

$$CKB = 02 \cdot 04 + T \cdot /ME + ME \cdot CD$$

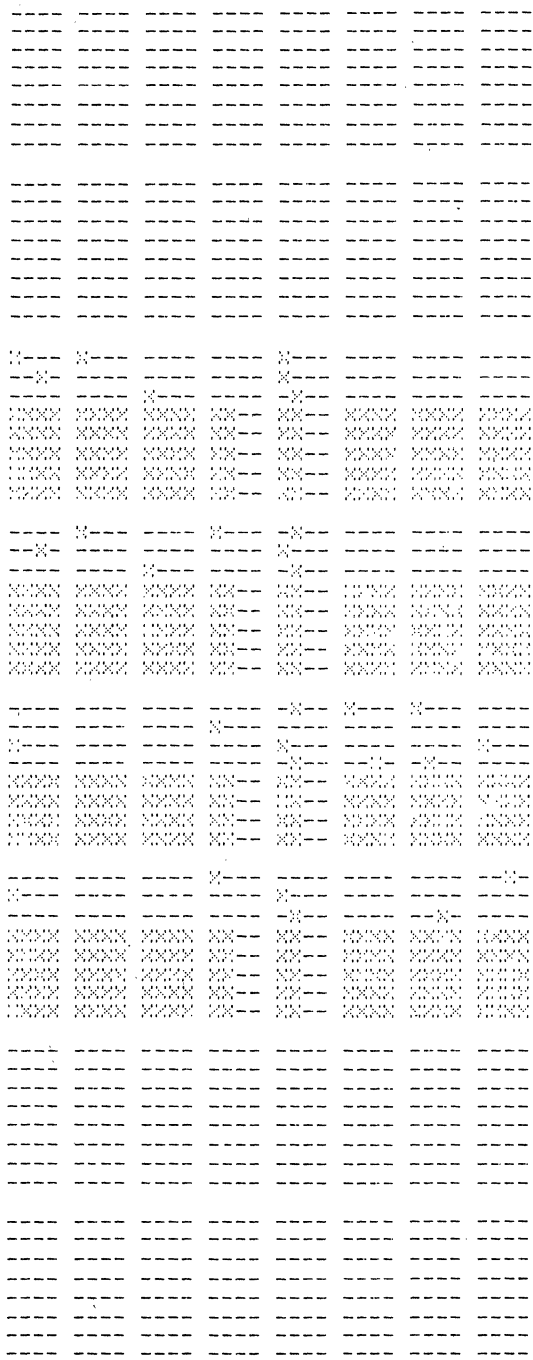
DESCRIPTION:

PORTION OF FLOPPY DISC CONTROL LOGIC

Minidiskette Control Logic Design Specification.

Portion of Micro Floppy Control Logic

Fuse Pattern PAL14H4



T♦D1♦ME
 DCF♦ME
 ME♦MCF

DE♦D1♦ME
 DCF♦ME
 ME♦MCF

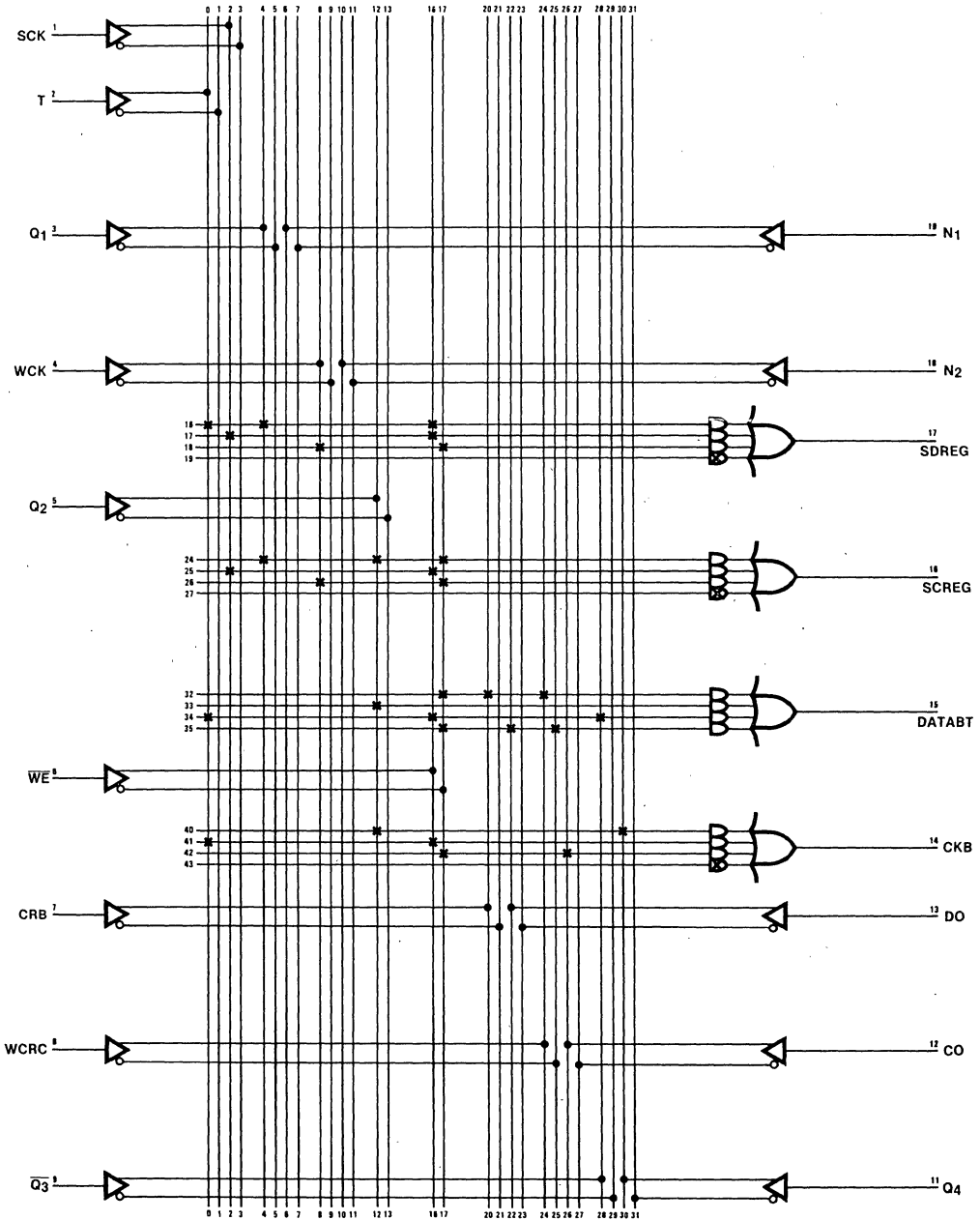
DE♦ME♦MCF
 DE
 T♦ME♦D3
 MCF♦ME♦D0

DE♦D4
 T♦ME
 ME♦D0

Minidiskette Control Logic, 14H4 Fuse Pattern.

Portion of Micro Floppy Control Logic

Logic Diagram PAL14H4

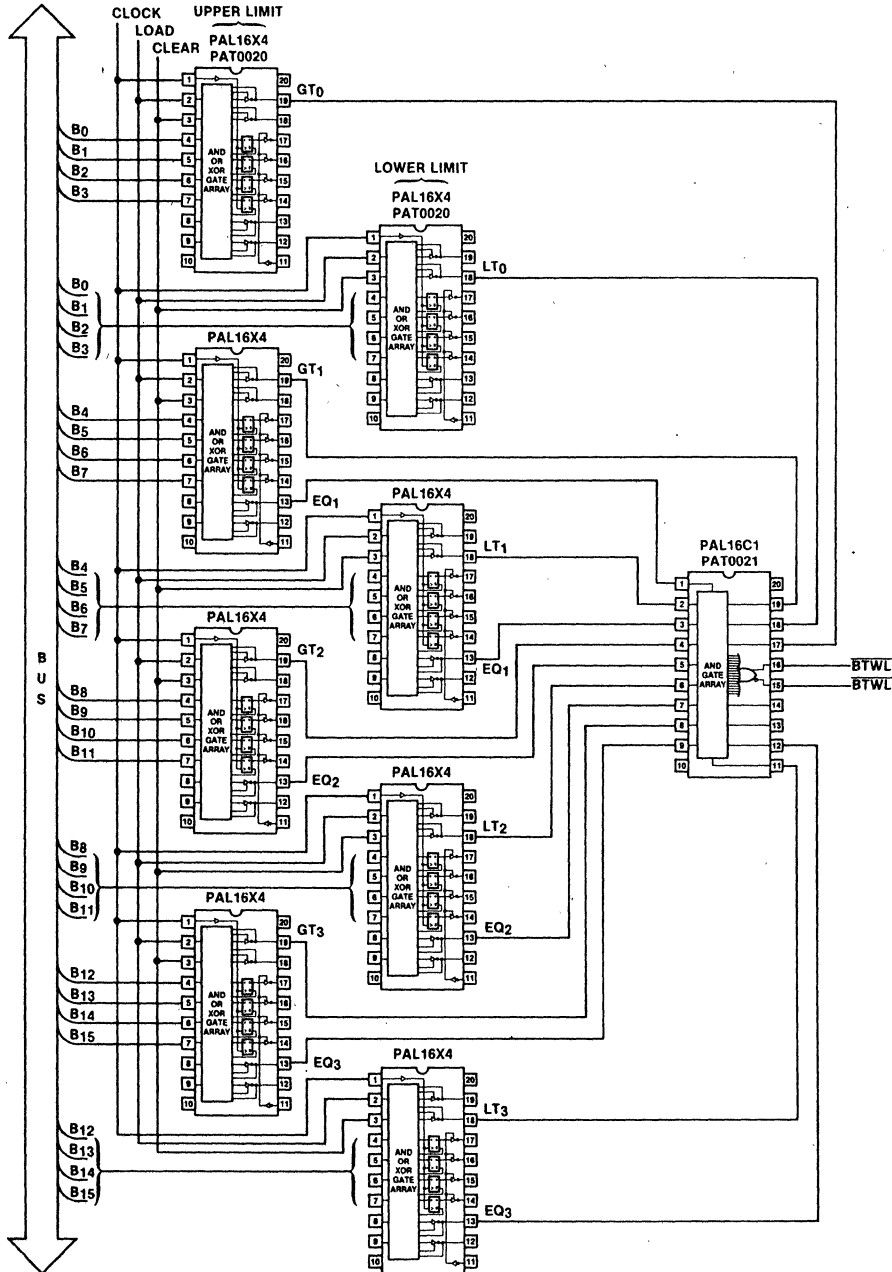


Minidiskette Control Logic, Coded 14H4 PAL Logic Diagram.

BETWEEN LIMITS COMPARATOR/ REGISTER

It is often needed to keep data between limits as it is processed, or to halt a process when limits are reached. This may be done for system security, or as a means of self-checking. The checker described here might

search for a specific value, search for missing values: values either in or out of a certain range. The sample circuit shown monitors a 16-bit bus, using two PAL types, and latches a complementary pair of BTWL status signals into its output registers.



Limit Checker Combinatorial Logic Diagram.

PAL16X4
PART0020

PAL DESIGN SPECIFICATION

BETWEEN LIMITS COMPARATOR REGISTER

A0 LOAD CLEAR B0 B1 B2 B3 NC NC AND YE NC E0 A3 A2 A1 A0 <LT >GT VCC

$$\text{IF (VCC) LT} = (\text{A3} \cdot \text{B3}) + (\text{A2} \cdot \text{B2}) + (\text{A1} \cdot \text{B1}) + (\text{A0} \cdot \text{B0}) + (\text{A3.E0.B3}) + (\text{A2.E0.B2}) + (\text{A1.E0.B1}) + (\text{A0.E0.B0})$$

$$\text{IF (VCC) GT} = (\text{A3} \cdot \text{B3}) + (\text{A2} \cdot \text{B2}) + (\text{A1} \cdot \text{B1}) + (\text{A0} \cdot \text{B0}) + (\text{A3.E0.B3}) + (\text{A2.E0.B2}) + (\text{A1.E0.B1}) + (\text{A0.E0.B0})$$

$$\text{A0} := (\text{A0} \cdot \text{LOAD} \cdot \text{CLEAR}) + (\text{B0} \cdot \text{LOAD} \cdot \text{CLEAR})$$

$$\text{A1} := (\text{A1} \cdot \text{LOAD} \cdot \text{CLEAR}) + (\text{B1} \cdot \text{LOAD} \cdot \text{CLEAR})$$

$$\text{A2} := (\text{A2} \cdot \text{LOAD} \cdot \text{CLEAR}) + (\text{B2} \cdot \text{LOAD} \cdot \text{CLEAR})$$

$$\text{A3} := (\text{A3} \cdot \text{LOAD} \cdot \text{CLEAR}) + (\text{B3} \cdot \text{LOAD} \cdot \text{CLEAR})$$

$$\text{IF (VCC) E0} = (\text{A3.E0.B3}) + (\text{A2.E0.B2}) + (\text{A1.E0.B1}) + (\text{A0.E0.B0})$$

DESCRIPTION:

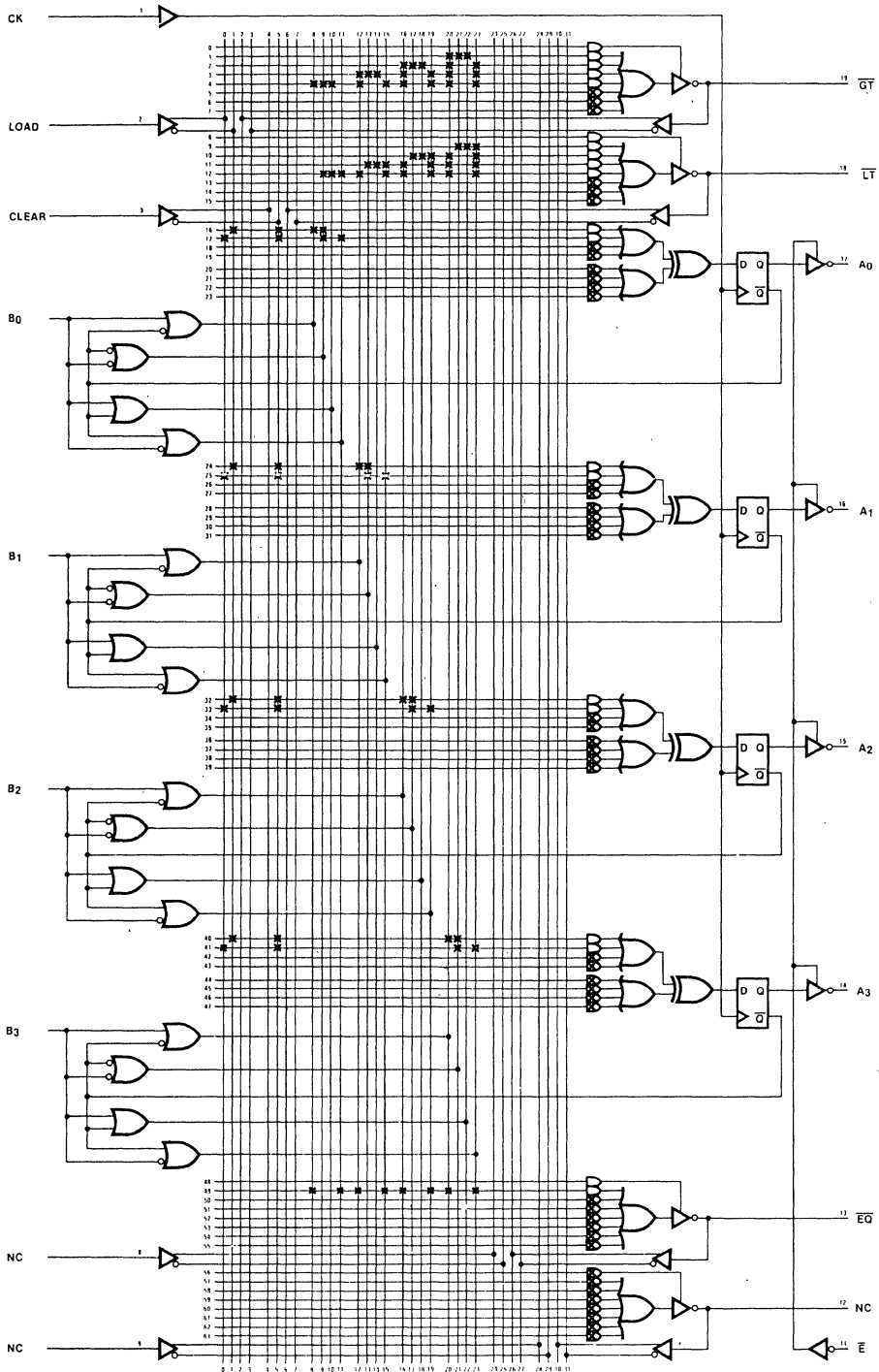
THE DEVICE CONTINUOUSLY COMPARES THE VALUE OF BUS, B, WITH THE VALUE OF REGISTER A AND REPORTS THE STATUS ON OUTPUTS GT, LT, AND E0. GT INDICATES THAT B IS GREATER THAN A. LT INDICATES THAT B IS LESS THAN A. E0 INDICATES THAT A IS EQUAL TO B. THE VALUE OF REGISTER A MAY BEAD BY LOWERING ENABLE LINE, YE. REGISTER A IS LOADED WITH THE VALUE ON BUS, B, WHEN THE LOAD LINE IS HIGH AND THE CLEAR LINE IS LOW ON THE LOW TO HIGH TRANSITION OF THE CLOCK.

LOAD	CLEAR	CLOCK	REGISTER A	OPERATION
L	L	L-H	A	NOP
H	H	L-H	ALL HIGH	CLEAR
H	L	L-H	B	LOAD B

PAL16X4 Limit Checker Design Specification.

Between Limits Comparator/Register

Logic Diagram PAL16X4



PAL16X4 Limit Checker Coded Logic Diagram.

Between Limits Comparator/Logic

Design Specification PAL16C1

PAL16C1
 PAT0021
 BETWEEN LIMITS COMPARATOR / LOGIC

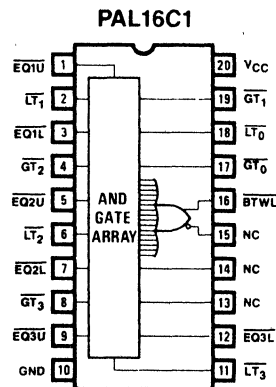
PAL DESIGN SPECIFICATION

/EQ1U /LT1 /EQ1L /GT2 /EQ2U /LT2 /EQ2L /GT3 /EQ3U GND
 /LT3 /EQ3L NC NC NC /BTWL /GT0 /LT0 /GT1 VCC

$$\begin{aligned} \text{/BTWL} = & \text{GT3} + \text{GT2} \cdot \text{EQ3U} + \text{GT1} \cdot \text{EQ3U} \cdot \text{EQ2U} + \text{GT0} \cdot \text{EQ3U} \cdot \text{EQ2U} \cdot \text{EQ1U} + \\ & \text{LT3} + \text{LT2} \cdot \text{EQ3L} + \text{LT1} \cdot \text{EQ3L} \cdot \text{EQ2L} + \text{LT0} \cdot \text{EQ3L} \cdot \text{EQ2L} \cdot \text{EQ1L} \end{aligned}$$

DESCRIPTION:

THE BETWEEN LIMITS LOGIC DETERMINES THE BTWL STATUS AS A FUNCTION OF THE GT, LT AND EQ STATUS FROM THE COMPARATOR REGISTERS.

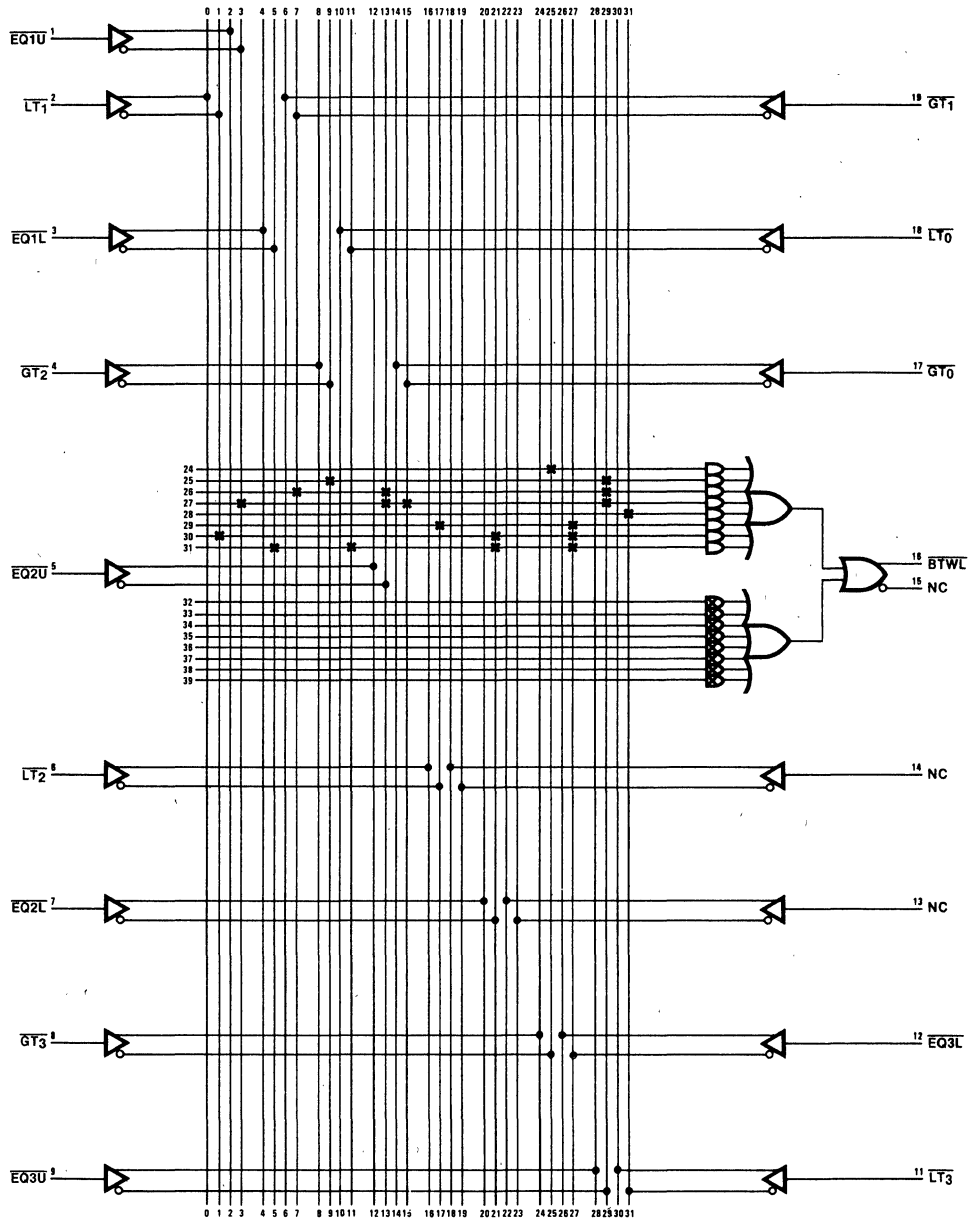


Logic Symbol

PAL16C1 Limit Checker Design Specification.

Between Limits Comparator/Logic

Logic Diagram PAL16C1



PAL16C1 Limit Checker Coded Logic Diagram.

8-BIT I/O PRIORITY INTERRUPT ENCODER WITH REGISTERS

Design Specification PAL16R4

Application Suggestions

PAL16R4

PAL DESIGN SPECIFICATION

PAT0005

8 BIT I/O PRIORITY INTERRUPT ENCODER WITH REGISTERS

CK I1 I2 I3 I4 I5 I6 I7 I8 GND /E NC NC 04 03 02 01 NC NC VCC

$$\overline{01} := \overline{I1 \cdot I2} + \overline{I1 \cdot I2 \cdot I3 \cdot I4} + \overline{I1 \cdot I2 \cdot I3 \cdot I4 \cdot I5 \cdot I6} + \overline{I1 \cdot I2 \cdot I3 \cdot I4 \cdot I5 \cdot I6 \cdot I7 \cdot I8}$$

$$\overline{02} := \overline{I1 \cdot I2 \cdot I3} + \overline{I1 \cdot I2 \cdot I3 \cdot I4} + \overline{I1 \cdot I2 \cdot I3 \cdot I4 \cdot I5 \cdot I6 \cdot I7} + \overline{I1 \cdot I2 \cdot I3 \cdot I4 \cdot I5 \cdot I6 \cdot I7 \cdot I8}$$

$$\overline{03} := \overline{I1 \cdot I2 \cdot I3 \cdot I4 \cdot I5} + \overline{I1 \cdot I2 \cdot I3 \cdot I4 \cdot I5 \cdot I6} + \overline{I1 \cdot I2 \cdot I3 \cdot I4 \cdot I5 \cdot I6 \cdot I7} + \overline{I1 \cdot I2 \cdot I3 \cdot I4 \cdot I5 \cdot I6 \cdot I7 \cdot I8}$$

$$\overline{04} := I1 + I2 + I3 + I4 + I5 + I6 + I7 + I8$$

DESCRIPTION:

THE I/O PRIORITY INTERRUPT ENCODER, PRIORITIZED 8 I/O LINES (I1 THRU I8) OUTPUTTING 111 (03,02,01 RESPECTIVELY) FOR THE HIGHEST PRIORITY I/O DEVICE (I1) AND 000 FOR AN INTERRUPT FROM THE LOWEST PRIORITY I/O DEVICE (I8). OUTPUT 04 SERVES AS THE INTERRUPT FLAG AND GOES LOW WHEN ANY OF THE 8 I/O INPUTS GO HIGH. THE PRIORITY INTERRUPT ENCODER REGISTERS ARE UPDATED ON THE RISING EDGE OF THE CLOCK INPUT (CK). THE 3-STATE OUTPUTS ARE HIGH-Z WHEN THE ENABLE LINE (/E) IS HIGH AND ENABLED WHEN THE ENABLED LINE (/E) IS LOW.

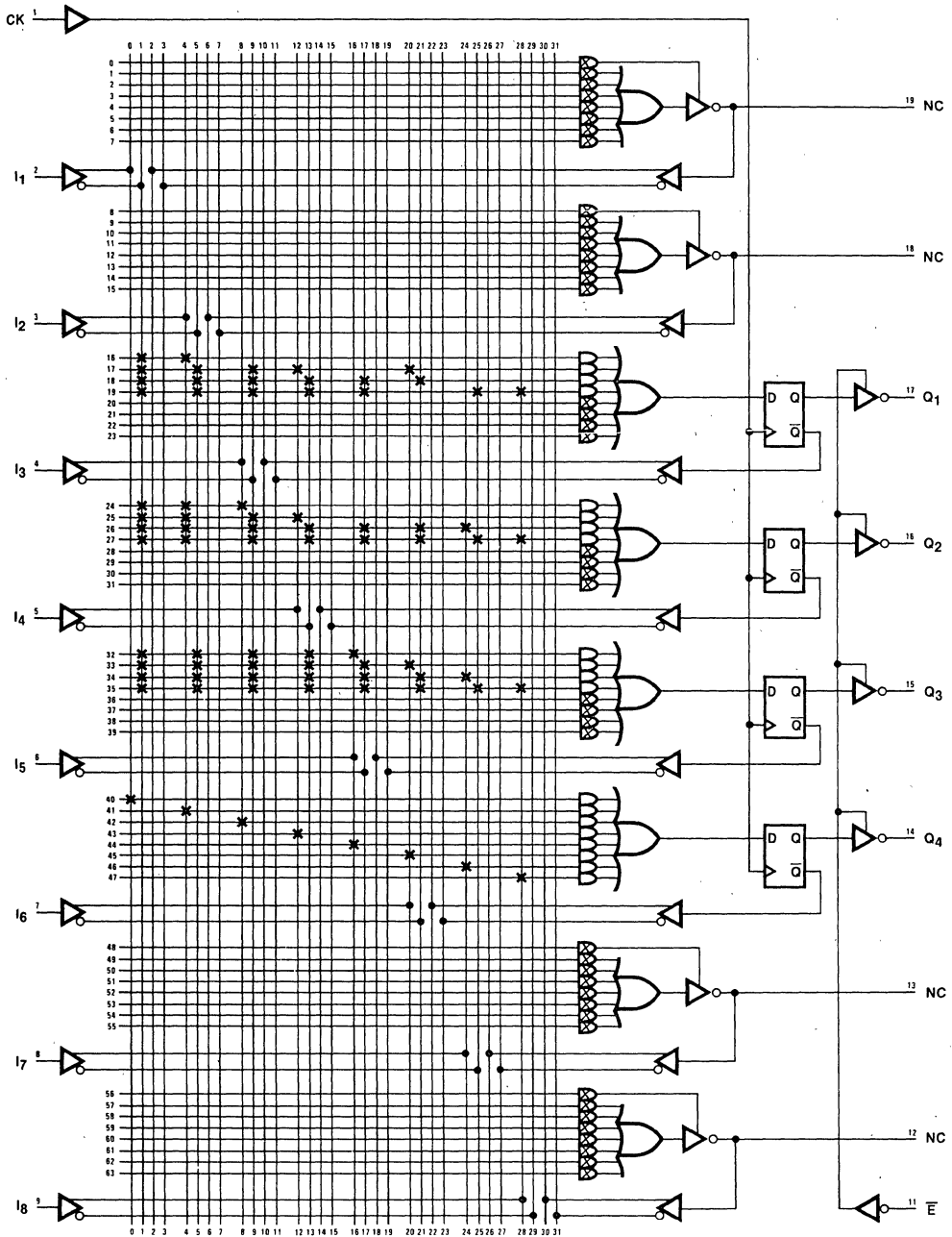
TRUTH TABLE

I	I	I	I	I	I	I	I	0	0	0		
E	8	7	6	5	4	3	2	1	4	3	2	1
H	X	X	X	X	X	X	X	X	Z	Z	Z	Z
L	X	X	X	X	X	X	X	H	L	H	H	H
L	X	X	X	X	X	X	H	L	L	H	H	L
L	X	X	X	X	H	L	L	L	L	H	L	H
L	X	X	X	H	L	L	L	L	L	H	L	L
L	X	X	H	L	L	L	L	L	L	L	H	L
L	X	H	L	L	L	L	L	L	L	L	L	H
L	H	L	L	L	L	L	L	L	L	L	L	L
L	L	L	L	L	L	L	L	L	H	H	H	H

Eight-Bit Priority Interrupt Encoder with Registers, Designs Specification.

8 Bit I/O Priority Interrupt Encoder with Registers

Design Specification PAL16R4



PAL16R4 Eight-Bit Priority Interrupt Encoder with Registers, Coded Logic Diagram.

QUADRUPLE 3-LINE/1-LINE DATA SELECTOR MULTIPLEXER

Design Specification PAL14H4

PAL14H4

PAL DESIGN SPECIFICATION

PAT0016

QUADRUPLE 3-LINE-TO-1-LINE DATA SELECTOR MULTIPLEXER

1A 2A 3A 4A 1B 2B 3B 4B 1C 10 GND 2C 3C 4C 4Y 3Y 2Y 1Y S1 S0 VCC

$$1Y = 1A \cdot S0 \cdot S1 + 1B \cdot S0 \cdot S1 + 1C \cdot S0 \cdot S1$$

$$2Y = 2A \cdot S0 \cdot S1 + 2B \cdot S0 \cdot S1 + 2C \cdot S0 \cdot S1$$

$$3Y = 3A \cdot S0 \cdot S1 + 3B \cdot S0 \cdot S1 + 3C \cdot S0 \cdot S1$$

$$4Y = 4A \cdot S0 \cdot S1 + 4B \cdot S0 \cdot S1 + 4C \cdot S0 \cdot S1$$

DESCRIPTION:

A 4-BIT WORD IS SELECTED FROM ONE OF THREE SOURCES AND IS ROUTED TO THE FOUR OUTPUTS. TRUE DATA IS PRESENTED AT THE OUTPUTS. IF INVERTED DATA IS DESIRED, USE THE SAME EQUATIONS WITH THE PAL14L4.

```

-----
!S0 !S1 ! OUTPUTS !
! L ! L ! A DATA !
! H ! L ! B DATA !
! L ! H ! C DATA !
! H ! H !  LOW  !
-----

```

```

-----
1A 1 + + 20 VCC
! ! !
2A 2 + + 19 S0
! ! !
3A 3 + + 18 S1
! ! !
4A 4 + + 17 1Y
! ! !
1B 5 + + 16 2Y
! ! !
2B 6 + + 15 3Y
! ! !
3B 7 + + 14 4Y
! ! !
4B 8 + + 13 4C
! ! !
1C 9 + + 12 3C
! ! !
GND 10 + + 11 2C
-----

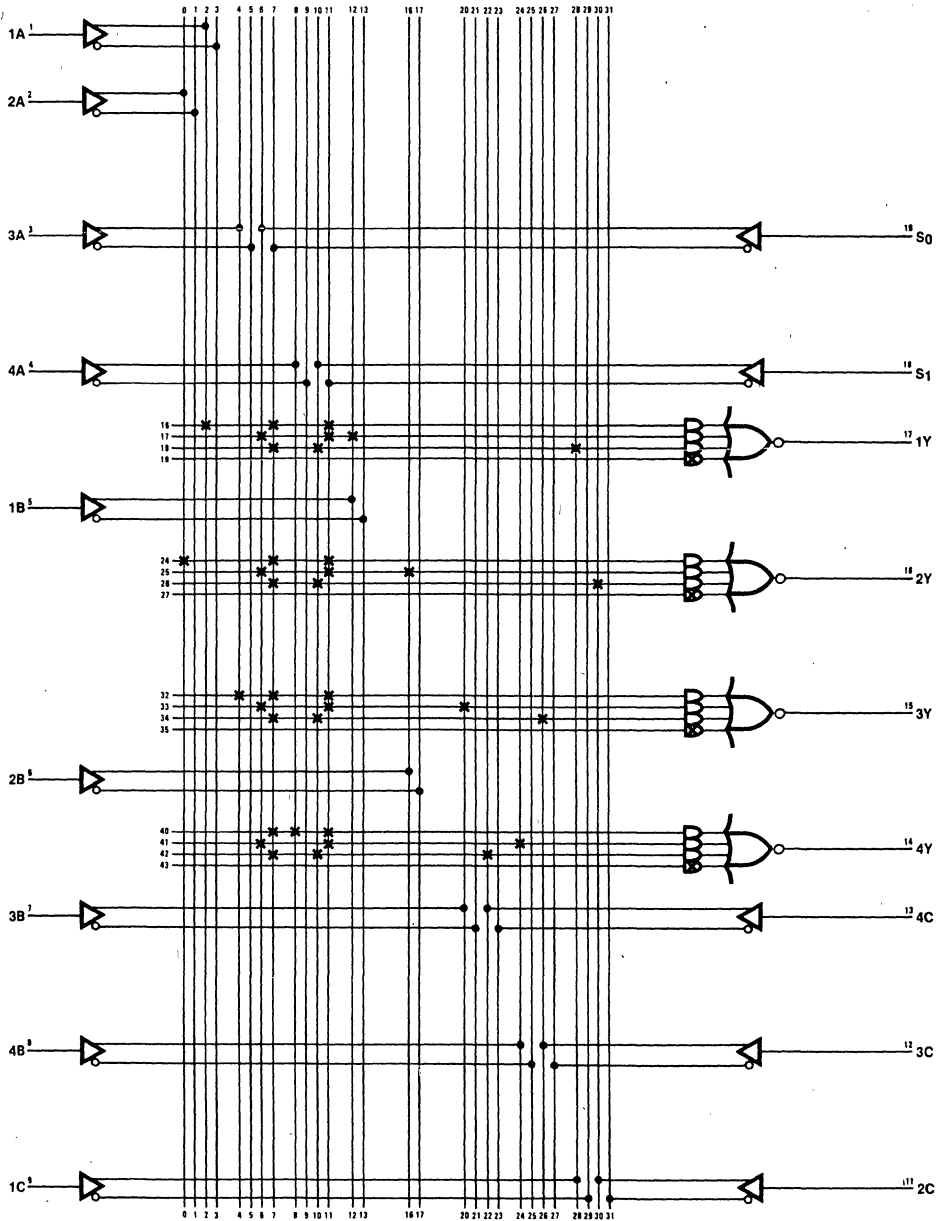
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PINOUT

Quad 3-to-1 Data Selector-Multiplexer, Design Specification.

Quadruple 3-Line/1-Line
Data Selector Multiplexer

Logic Diagram PAL14H4



PAL14H4 Quad 3-to-1 Data Selector Multiplexer, Coded Logic Diagram

4-BIT COUNTER WITH 2 INPUT MUX

Design Specification PAL16R4

PAL16R4

PAL DESIGN SPECIFICATION

PAT0034

4-BIT COUNTER WITH 2 INPUT MUX

CLOCK A0 A1 A2 A3 B0 B1 B2 B3 GND VE COUT I1 I0 Q3 Q2 Q1 Q0 IO CIN VCC

$$Q0 := \overline{I1} \overline{I0} \overline{Q0} + \overline{I1} I0 \overline{A0} + I1 \overline{I0} \overline{B0} + I1 I0 \overline{CIN} \overline{Q0} + I1 I0 CIN Q0$$

$$Q1 := \overline{I1} \overline{I0} \overline{Q1} + \overline{I1} I0 \overline{A1} + I1 \overline{I0} \overline{B1} + I1 I0 \overline{CIN} \overline{Q1} + I1 I0 CIN Q1 \overline{Q0} + I1 I0 \overline{Q1} \overline{Q0}$$

$$Q2 := \overline{I1} \overline{I0} \overline{Q2} + \overline{I1} I0 \overline{A2} + I1 \overline{I0} \overline{B2} + I1 I0 \overline{CIN} \overline{Q2} + I1 I0 CIN Q2 \overline{Q1} \overline{Q0} + I1 I0 \overline{Q2} \overline{Q1} + I1 I0 \overline{Q2} \overline{Q0}$$

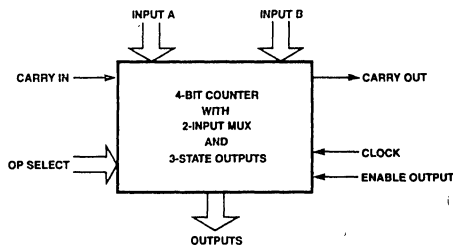
$$Q3 := \overline{I1} \overline{I0} \overline{Q3} + \overline{I1} I0 \overline{A3} + I1 \overline{I0} \overline{B3} + I1 I0 \overline{CIN} \overline{Q3} + I1 I0 CIN Q3 \overline{Q2} \overline{Q1} \overline{Q0} + I1 I0 \overline{Q3} \overline{Q2} + I1 I0 \overline{Q3} \overline{Q1} + I1 I0 \overline{Q3} \overline{Q0}$$

$$IF(VCC) \overline{COUT} = \overline{CIN} + \overline{Q3} + \overline{Q2} + \overline{Q1} + \overline{Q0}$$

DESCRIPTION:

THE 4-BIT COUNTER LOADS A OR B FROM THE MUX, OR COUNTS UP. THE THREE STATE OUTPUTS ARE ACTIVE WHEN VE IS LOW.

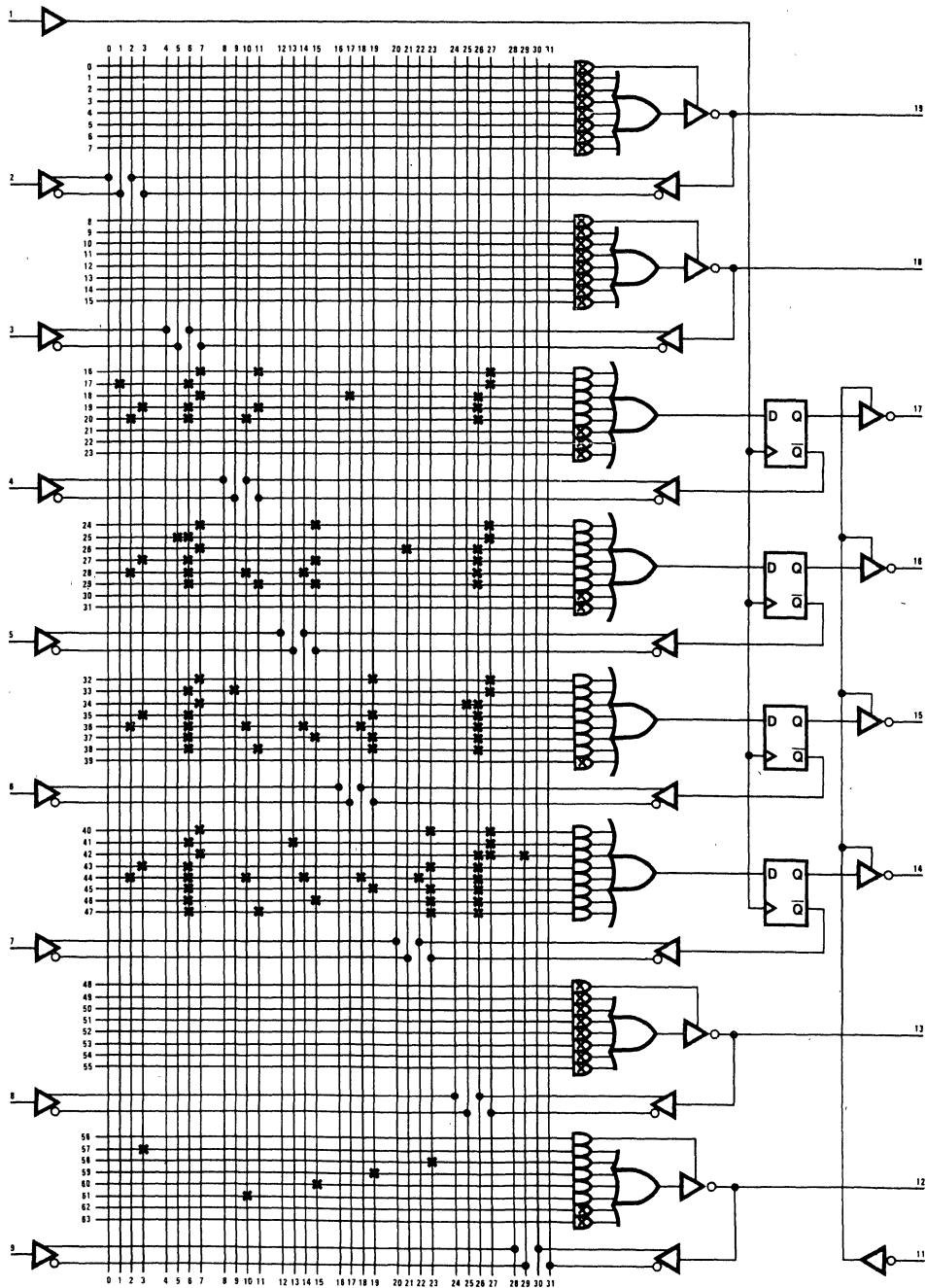
! VE !	I1 I0 !	CIN !	CLOCK !	OUTPUT Q !	OPERATION !
! L !	! L L !	! X !	! L-H !	! 0 !	! NOP !
! L !	! L H !	! X !	! L-H !	! A !	! LOAD A !
! L !	! H L !	! X !	! L-H !	! B !	! LOAD B !
! L !	! H H !	! L !	! L-H !	! 0 !	! NOP !
! L !	! H H !	! H !	! L-H !	! 0 PLUS 1 !	! INCREMENT !



Four-Bit Counter with Two-Input Multiplex, Design Specification.

4-Bit Counter with 2 Input Mux

Logic Diagram PAL16R4



PAL16R4 Four-bit Counter with Two-Input Multiplex, Coded Logic Diagram.

4-BIT UP/DOWN COUNTER WITH SHIFT AND THREE-STATE OUTPUTS

Design Specification PAL16X4

PAL16X4
PART0026

PAL DESIGN SPECIFICATION

4 BIT UP/DOWN COUNTER WITH SHIFT AND THREE-STATE OUTPUTS

CLOCK I0 I1 B0 B1 B2 B3 I2 CLEAR GND /E /LID NC A3 A2 A1 A0 NC /RID VCC

IF (I2) I0 = I1 + I0 + /A0

A0 := /A0/I2/I1/I0 + /B0/I2/I1/I0 + /A1/I2/I1/I0 + /A0/I2/I1
 ++ /RID/I2/I1/I0 +
 /RID/I2/I1/I0 +
 /RID/I2/I1/I0 + CLEAR

A1 := /A1/I2/I1/I0 + /B1/I2/I1/I0 + /A2/I2/I1/I0 + /A1/I2/I1
 ++ /A0/I2/I1/I0 +
 /A0/RID/I2/I1/I0 +
 /A0/RID/I2/I1/I0 + CLEAR

A2 := /A2/I2/I1/I0 + /B2/I2/I1/I0 + /A3/I2/I1/I0 + /A2/I2/I1
 ++ /A1/I2/I1/I0 +
 /A1/A0/RID/I2/I1/I0 +
 /A1/A0/RID/I2/I1/I0 + CLEAR

A3 := /A3/I2/I1/I0 + /B3/I2/I1/I0 + /LID/I2/I1/I0 + /A3/I2/I1
 ++ /A2/I2/I1/I0 +
 /A2/A1/A0/RID/I2/I1/I0 +
 /A2/A1/A0/RID/I2/I1/I0 + CLEAR

IF (I2) /LID = /A3/I2/I1/I2 + /A3/A2/A1/A0/RID/I2/I1/I0 +
 /A3/A2/A1/A0/RID/I2/I1/I0

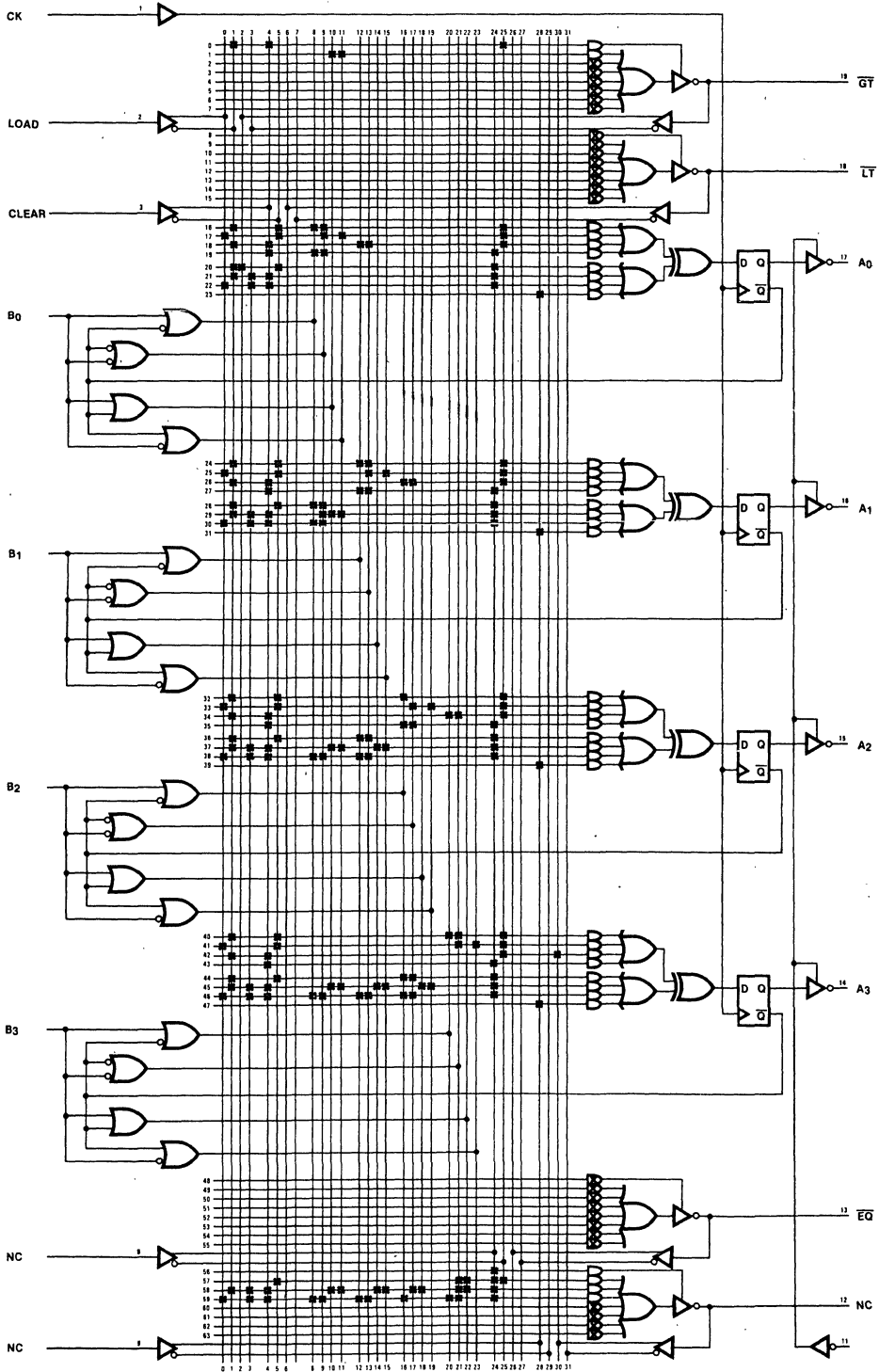
DESCRIPTION:

THE UP/DOWN COUNTER WITH SHIFT WILL LOAD, SHIFT, COUNT UP, COUNT DOWN, CLEAR OR NOP ON THE RISING EDGE OF THE CLOCK AS SPECIFIED BY THE INSTRUCTION. I, SHIFT I/O, CARRY AND BORROW SHARE THE SAME I/O LINES (/LID AND /RID). ACTIVE HIGH OUTPUTS, A, ARE ENABLED WHEN /E IS LOW. NOTE: THE IMPLIED EXCLUSIVE OR, ++, MUST BE PLACED BETWEEN THE FOURTH AND FIFTH PRODUCT TERMS.

INPUTS				OUTPUTS									
CLEAR	I2	I1	I0	LID	RID	CLOCK	LID	A3	A2	A1	A0	RID	OPERATION
L	L	L	L	X	X	L-H	Z	A3	A2	A1	A0	Z	NOP
L	L	L	H	X	X	L-H	Z	B3	B2	B1	B0	Z	LOAD B
L	L	H	L	X	Z	L-H	Z	R1	A3	A2	A1	A1	SHIFT RT
L	L	H	H	X	X	L-H	Z	ALL HIGH			Z	SET	
L	H	L	L	Z	LI	L-H	A2	A2	A1	A0	LI	Z	SHIFT LT
L	H	L	H	Z	X	L-H	L	ALL HIGH			Z	SET	
L	H	H	L	Z	CIN	L-H	COU	A PLUS ONE			Z	INC IF CIN	
L	H	H	H	Z	BIN	L-H	BOUT	A MINUS ONE			Z	DEC IF BIN	
H	X	X	X	X	X	L-H	Z	ALL LOW			Z	CLEAR	

Four-Bit Up/Down Counter with Shift and TRI-STATE (R) Outputs, Design Specification.

Application Suggestions



PAL16X4 Four-Bit Up/Down Counter with Shift and TRI-STATE (R) Outputs, Coded Logic Diagram.

ALU ACCUMULATOR

Design Specification PAL16A4

PAL16A4
PAT0026
ALU ACCUMULATOR

PAL DESIGN SPECIFICATION

CLOCK I0 I1 B0 B1 B2 B3 I2 I3 GND E LIO P A3 A2 A1 A0 G CIN VCC

$$A0 := I3 \cdot I2 \cdot I1 \cdot I0 \cdot A0 \cdot E0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot CIN + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A1 + I3 \cdot A0 + CARRY0$$

$$A1 := I3 \cdot I2 \cdot I1 \cdot I0 \cdot A1 \cdot E0 \cdot B1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A1 \cdot B1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 + I3 \cdot A1 + CARRY1$$

$$A2 := I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 \cdot E0 \cdot B2 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B2 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B2 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 \cdot B2 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 + I3 \cdot A2 + CARRY2$$

$$A3 := I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot E0 \cdot B3 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B3 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B3 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot B3 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot LIO + I3 \cdot A3 + CARRY3$$

$$\text{IF} \cdot \text{VCC} \cdot G = I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot B3 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot B3 \cdot A2 \cdot B2 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot B3 \cdot A2 \cdot B2 \cdot A1 \cdot B1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot B3 \cdot A2 \cdot B2 \cdot A1 \cdot B1 \cdot A0 \cdot B0$$

$$\text{IF} \cdot \text{VCC} \cdot P = I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot B3 \cdot A2 \cdot B2 \cdot A1 \cdot B1 \cdot A0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot A2 \cdot A1 \cdot A0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot B3 \cdot B2 \cdot B1 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot B3 \cdot A2 \cdot B2 \cdot A1 \cdot B1 \cdot A0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A3 \cdot B3 \cdot A2 \cdot B2 \cdot A1 \cdot B1 \cdot A0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 \cdot A1 \cdot A0 \cdot CIN + I3 \cdot I2 \cdot I1 \cdot I0 \cdot LIO \cdot A3 \cdot A2 \cdot A1$$

$$\text{IF} \cdot I3 \cdot I2 \cdot I1 \cdot I0 \cdot LIO = A3$$

$$\text{IF} \cdot I3 \cdot I2 \cdot I1 \cdot I0 \cdot CIN = A0$$

NOTE: CARRY0 = I3 · I2 · I1 · I0 · CIN

$$\text{CARRY1} = I3 \cdot I2 \cdot I1 \cdot I0 \cdot A0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A0 \cdot B0 \cdot CIN$$

$$\text{CARRY2} = I3 \cdot I2 \cdot I1 \cdot I0 \cdot A1 \cdot B1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A1 \cdot B1 \cdot A0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A1 \cdot B1 \cdot A0 \cdot B0 \cdot CIN$$

$$\text{CARRY3} = I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 \cdot B2 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 \cdot B2 \cdot A1 \cdot B1 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 \cdot B2 \cdot A1 \cdot B1 \cdot A0 \cdot B0 + I3 \cdot I2 \cdot I1 \cdot I0 \cdot A2 \cdot B2 \cdot A1 \cdot B1 \cdot A0 \cdot B0 \cdot CIN$$

DESCRIPTION:

THE ALU ACCUMULATOR LOADS THE A-REGISTER WITH ONE OF EIGHT OPERANDS ON THE RISING EDGE OF THE CLOCK. G AND P OUTPUT GENERATE AND PROPAGATE ON THE ADD INSTRUCTION. P OUTPUTS DP = ZERO ON INSTRUCTIONS 1,2,3,5,6,7.

INPUT		OUTPUT					OPERATION							
I3	I2	I1	I0	LIO	CIN	LIO	A3	A2	A1	A0	CIN			
L	L	L	L	L	L	L	A	PLUS	B			ADD	A=A PLUS B	
L	L	L	L	L	L	L	A	PL	B	PL	1	ADD	A=A PLUS B PLUS 1	
L	L	L	L	H	L	L	A3	A2	A1	A0		NOF	A=A	
L	L	H	L	L	L	L	B3	B2	B1	B0		LOAD	A=B	
L	L	H	H	L	L	L	A	AND	B			AND	A=A AND B	
L	H	L	L	L	L	L	B3	B2	B1	B0		LOADCOMP	A=-B	
L	H	L	H	L	L	L	A	OF	B			OP	A=A AND B	
L	H	H	L	L	L	LI	A2	A2	A1	A0	LI		SHIFT LEFT	
L	H	H	H	L	L	PI		PI	A3	A2	A1	A1	SHIFT RIGHT	
H	L	L	L	L	L	L	A3	A2	A1	A0			NOF	A=A

ALU Accumulator, Design Specification.

ALU Accumulator

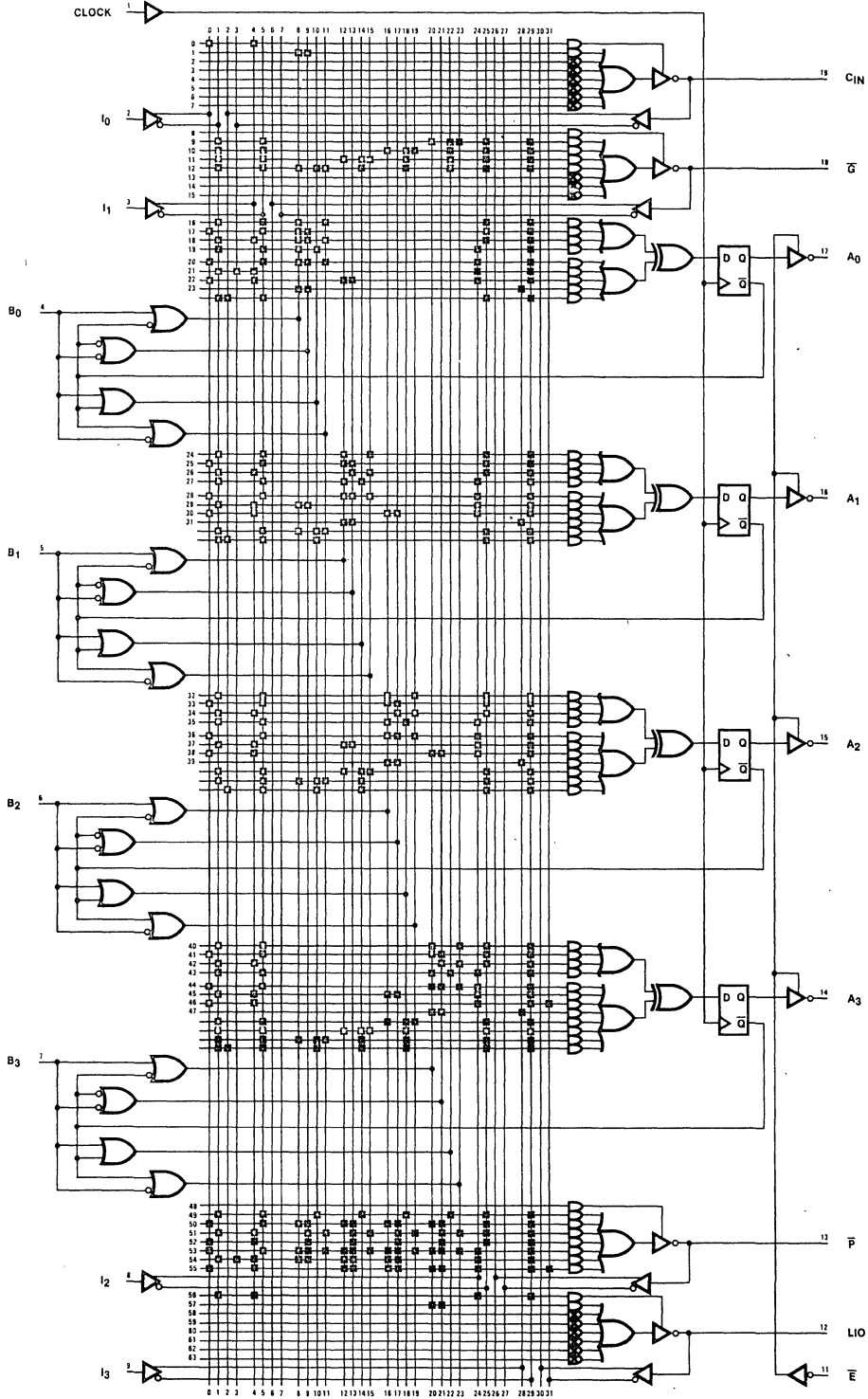
Fuse Pattern PAL16A4

N---	X---	----	----	----	----	N---	X---	/I3/I2/I1/I0
----	----	XX--	----	----	----	----	----	/A0
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
----	----	----	----	----	----	----	----	
-X--	-X--	----	----	----	N-XX	-X--	-X--	/I3/I2/I1/I0/A3/B3
-X--	-X--	----	----	N-XX	-X--	-X--	-X--	/I3/I2/I1/I0/A3/B3/A2/B2
-X--	-X--	----	N-XX	-X--	-X--	-X--	-X--	/I3/I2/I1/I0/A3/B3/A2/B2/A1
-X--	-X--	X-XX	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/A3/B3/A2/B2/A1+
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
----	----	----	----	----	----	----	----	
-X--	-X--	X-X	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/A0.E0.B0
X---	X---	XX--	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/A0
-X--	-X--	X-X	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/B0
-X--	-X--	X-X	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/B0
X---	X---	XX-X	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/A0/B0
-X-X	X---	----	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/CIN
X---	X---	----	XX--	----	----	-X--	-X--	/I3/I2/I1/I0/A1
----	----	XX--	----	----	----	N---	N---	I3/A0
----	----	----	----	----	----	----	----	
-X--	-X--	----	X-X	----	-X--	-X--	-X--	/I3/I2/I1/I0/A1.E0.E1
X---	X---	XX--	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/A1
-X--	-X--	----	X-X	----	-X--	-X--	-X--	/I3/I2/I1/I0/B1
-X--	-X--	----	X-X	----	-X--	-X--	-X--	/I3/I2/I1/I0/B1
X---	X---	XX-X	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/A1/B1
-X--	-X--	XX--	----	----	----	-X--	-X--	/I3/I2/I1/I0/A0
X---	X---	----	XX--	----	----	-X--	-X--	/I3/I2/I1/I0/A2
----	----	XX--	----	----	----	X---	X---	I3/A1
----	----	----	----	----	----	----	----	
-X--	-X--	----	N-X	----	-X--	-X--	-X--	/I3/I2/I1/I0/A2.E0.E2
X---	X---	----	XX--	----	-X--	-X--	-X--	/I3/I2/I1/I0/A2
-X--	-X--	----	X-X	----	-X--	-X--	-X--	/I3/I2/I1/I0/B2
-X--	-X--	----	X-X	----	-X--	-X--	-X--	/I3/I2/I1/I0/B2
X---	X---	----	XX-X	----	-X--	-X--	-X--	/I3/I2/I1/I0/A2/B2
-X--	-X--	XX--	----	----	-X--	-X--	-X--	/I3/I2/I1/I0/A1
X---	X---	----	XX--	----	-X--	-X--	-X--	/I3/I2/I1/I0/A3
----	----	XX--	----	----	----	X---	X---	I3/A2
----	----	----	----	----	----	----	----	
-X--	-X--	----	----	----	X-X	-X--	-X--	/I3/I2/I1/I0/A3.E0.E3
X---	X---	----	XX--	----	-X--	-X--	-X--	/I3/I2/I1/I0/A3
-X--	-X--	----	----	----	X-X	-X--	-X--	/I3/I2/I1/I0/B3
-X--	-X--	----	----	----	X-X	-X--	-X--	/I3/I2/I1/I0/B3
X---	X---	----	XX-X	----	-X--	-X--	-X--	/I3/I2/I1/I0/A3/B3
-X--	-X--	XX-X	XX-X	XX-X	-X--	-X--	-X--	/I3/I2/I1/I0/A3/B3/A2/B2
-X-X	X---	XX--	XX--	XX--	----	-X--	-X--	/I3/I2/I1/I0/A2/A1/A0/CIN
X---	X---	----	XX--	XX--	XX--	-X-X	-X-X	/I3/I2/I1/I0/LID/A3/A2/A1
----	----	----	----	----	----	----	----	
-X--	X---	----	----	----	----	X---	-X--	/I3/I2/I1/I0
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	/A3
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	
XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	XXXX	

ALU Accumulator, PAL16A4 Fuse Pattern.

ALU Accumulator

Logic Diagram PAL16A4



PAL16A4 ALU Accumulator, Coded Logic Diagram.



Physical Dimensions



PACKAGES

Dual-In-Line Packages

- (N) Devices ordered with "N" suffix are supplied in plastic molded dual-in-line packages. Molding material is a highly reliable compound suitable for military as well as commercial temperature range applications. Lead material is copper or alloy 42 with a hot solder dipped surface to allow ease of solderability.
- (J) Devices ordered with the "J" suffix are supplied in a CERDIP package (ceramic lid and base sealed with high temperature vitreous glass). Lead material is solder dipped alloy 42.
- (D) Devices ordered with the "D" suffix are supplied in side brazed, multi-layer, ceramic dual-in-line packages. The leads are Kovar or alloy 42 and either tin-plated, gold-plated, or solder-plated.
- (Q) Devices ordered with the "Q" suffix are supplied in either a "D" or "J" package, but with a UV window.

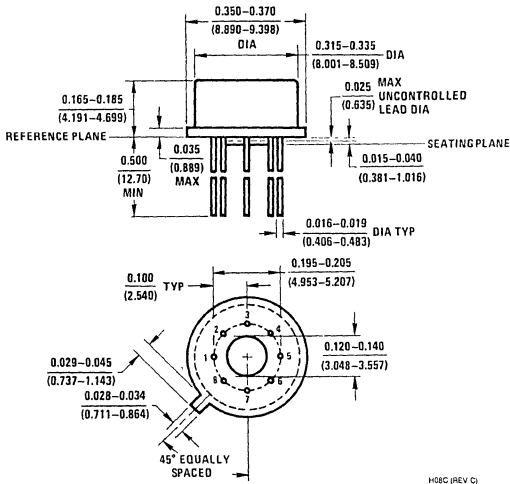
Metal Can Packages

- (H) Devices ordered with the "H" suffix are supplied in a metal can package. The cap is nickel finish and the leads are gold-plated Kovar. Gold free construction using epoxy D/A is also available, with a tin-plated finish.

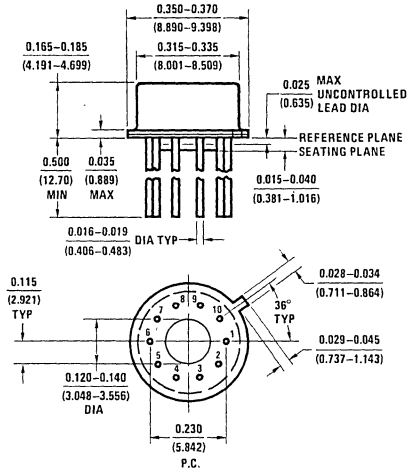
Flat Packages

- (F) Devices ordered with the "F" suffix are supplied in a multi-layer, ceramic bottom brazed flat package. The lid is plated alloy 42, and leads are gold-plated, tin-plated, or solder-plated alloy 42 or Kovar.
- (W) Devices ordered with the "W" suffix are supplied in a low-temperature ceramic flat package.

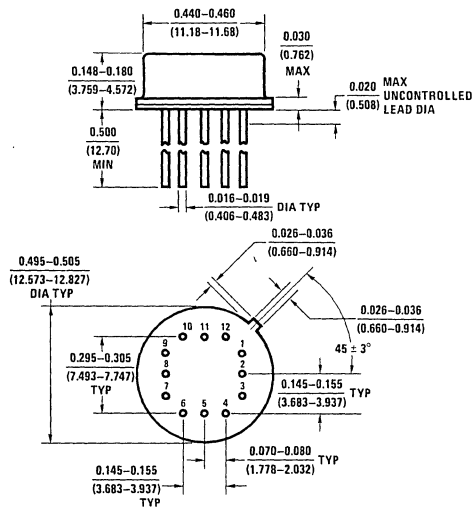
G12C package is replaced by H12C package.



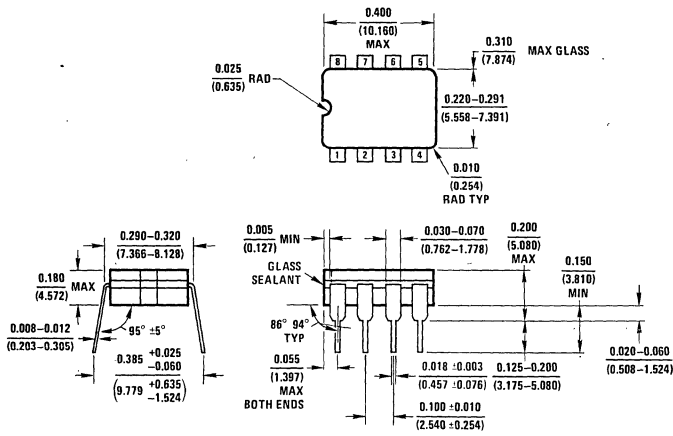
NS Package H08C
8-Lead TO-5 Metal Can Package (H)



NS Package H10C
10-Lead TO-5 Metal Can Package (H)
(Low Profile)

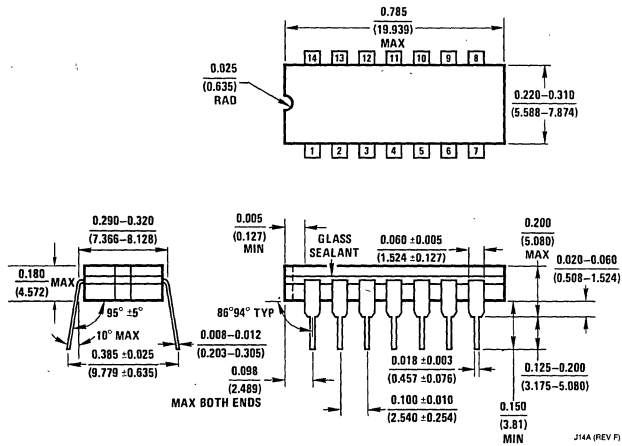


NS Package H12C
12-Lead TO-8 Metal Can Package (H)



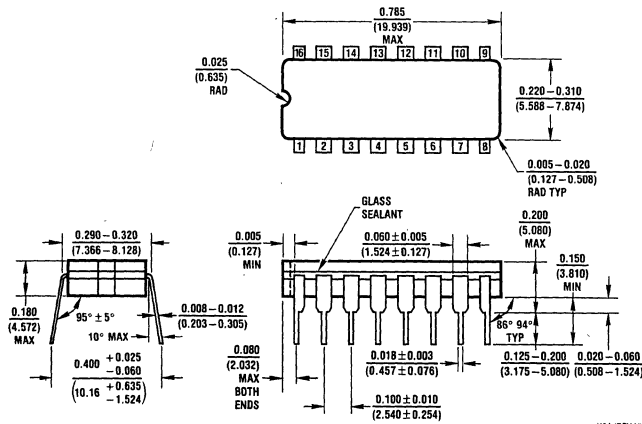
J08A (REV G)

NS Package J08A
8-Lead Cavity DIP (J)



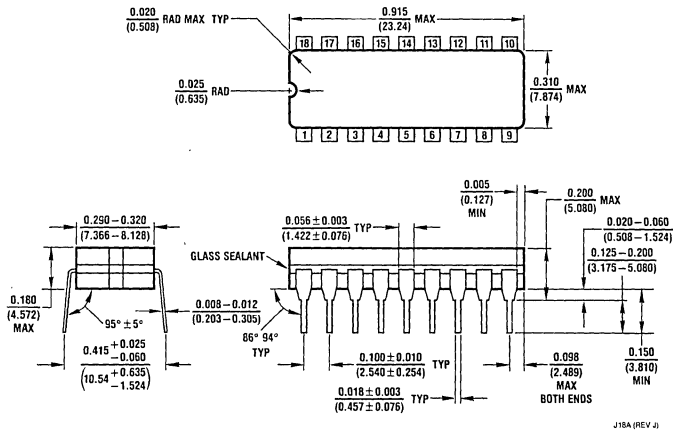
J14A (REV F)

NS Package J14A
14-Lead Cavity DIP (J)

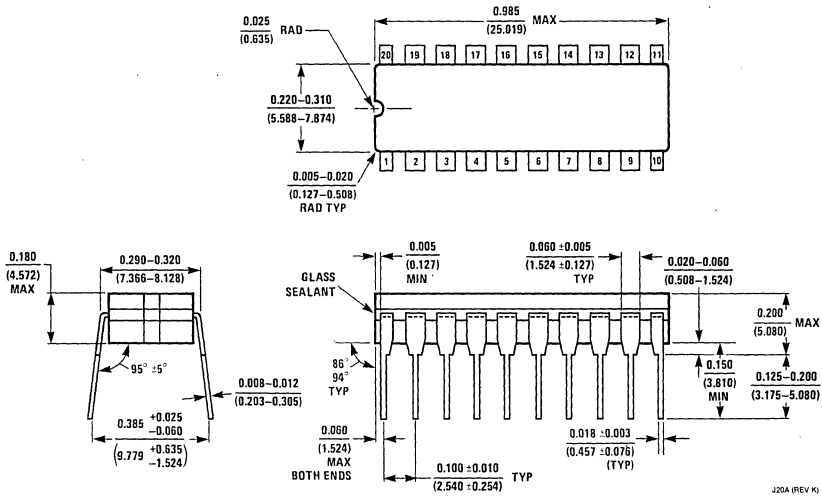


J16A (REV H)

NS Package J16A
16-Lead Cavity DIP (J)



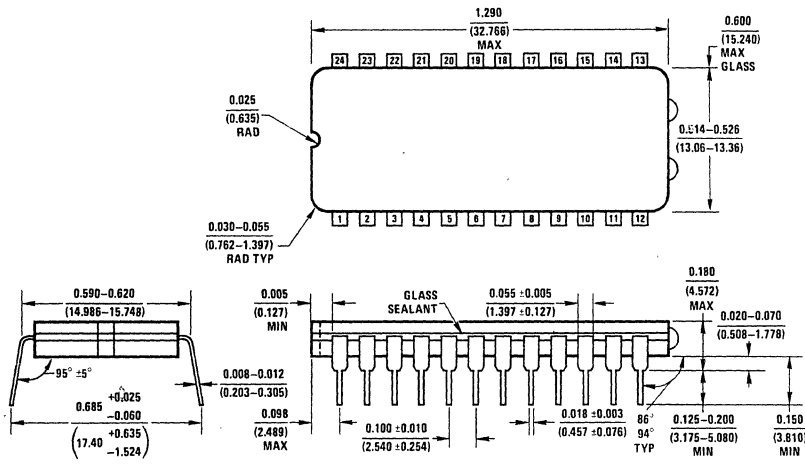
NS Package J18A
18-Lead Cavity DIP (J)



NS Package J20A
20-Lead Cavity DIP (J)

J20B package is replaced by J20A package.

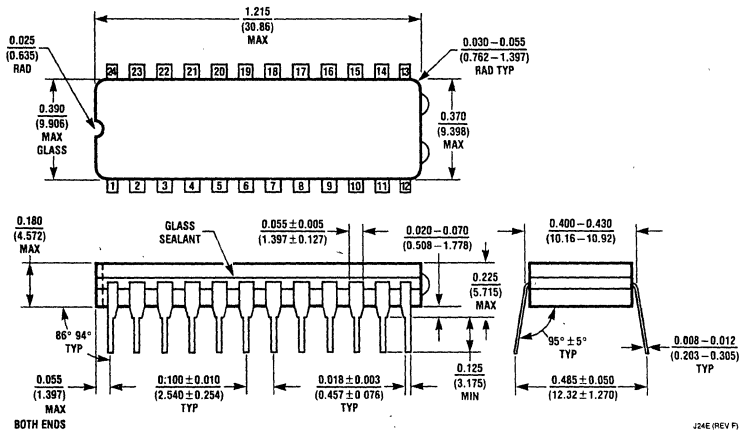
Physical Dimensions



J24A (REV H)

NS Package J24A
24-Lead Cavity DIP (J)

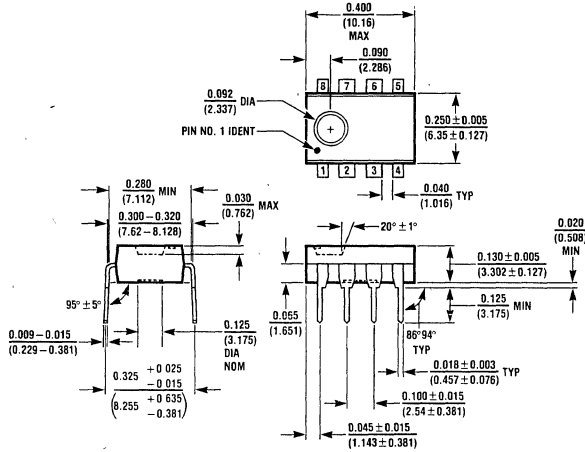
J24C package is replaced by J24A package.



J24E (REV F)

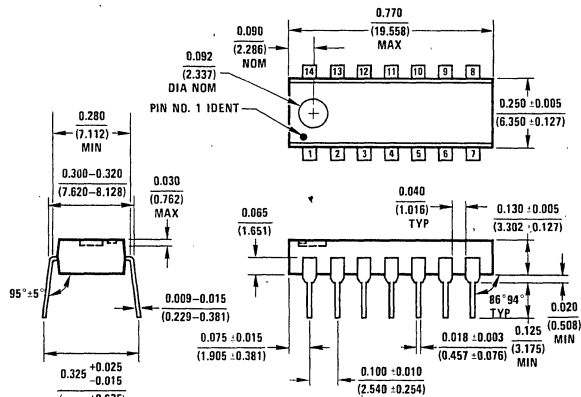
NS Package J24E
24-Lead Cavity DIP (J)

N08A package is replaced by N08E package.



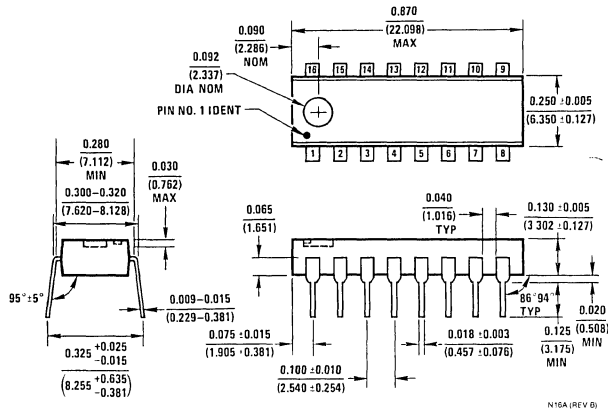
N08E (REV C)

NS Package N08E
8-Lead Molded DIP (N)

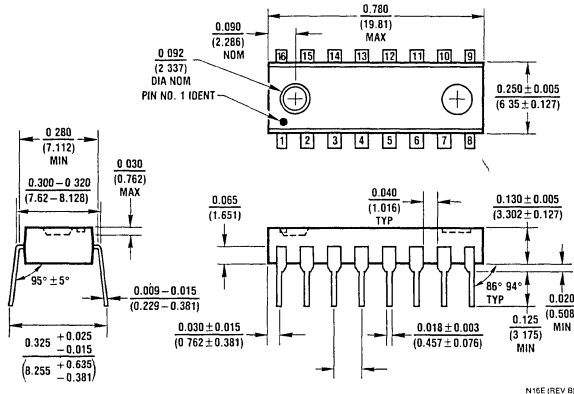


N14A (REV B)

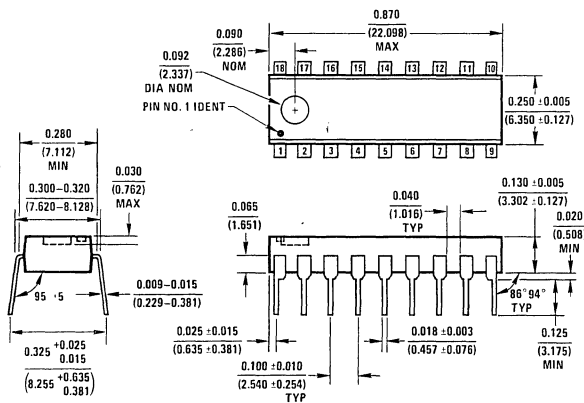
NS Package N14A
14-Lead Molded DIP (N)



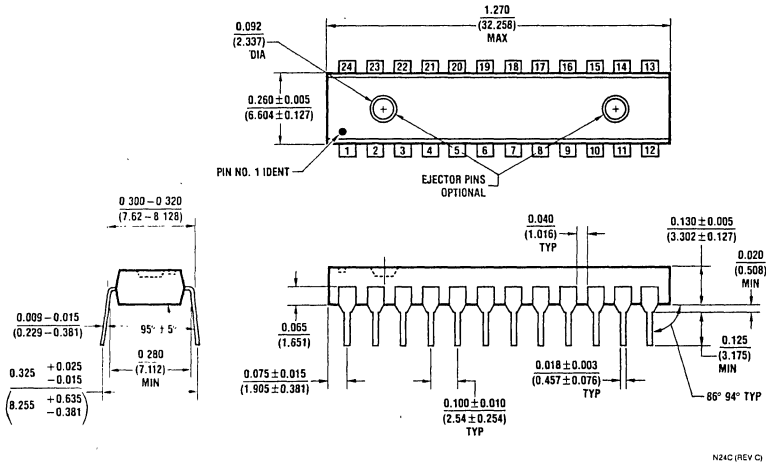
NS Package N16A
16-Lead Molded DIP (N)
(N16E may be substituted)



NS Package N16E
16-Lead Molded DIP (N)
(Substitute for N16A)

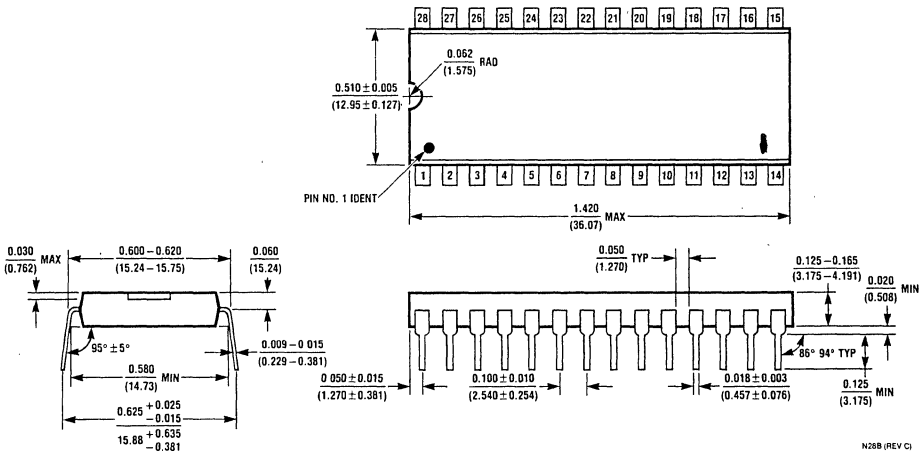


NS Package N18A
18-Lead Molded DIP (N)

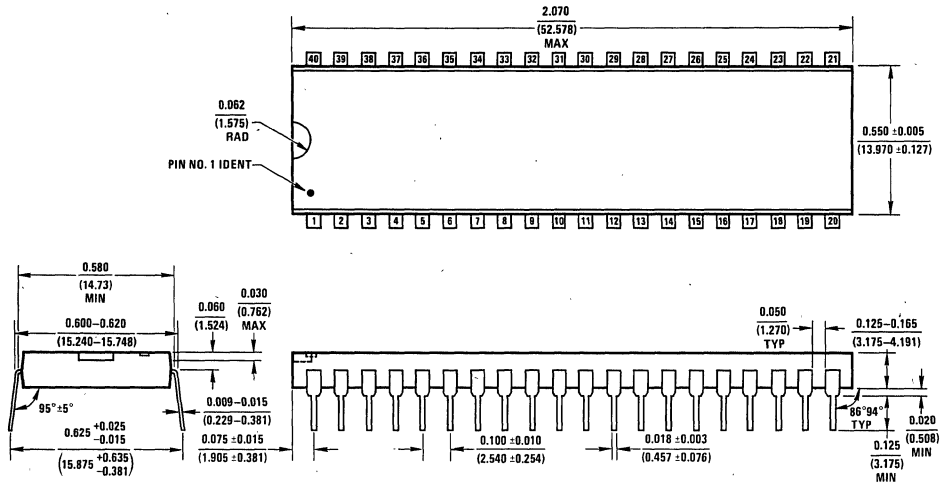


NS Package N24C
24-Lead Molded DIP (N)

N28A package is replaced by N28B package.

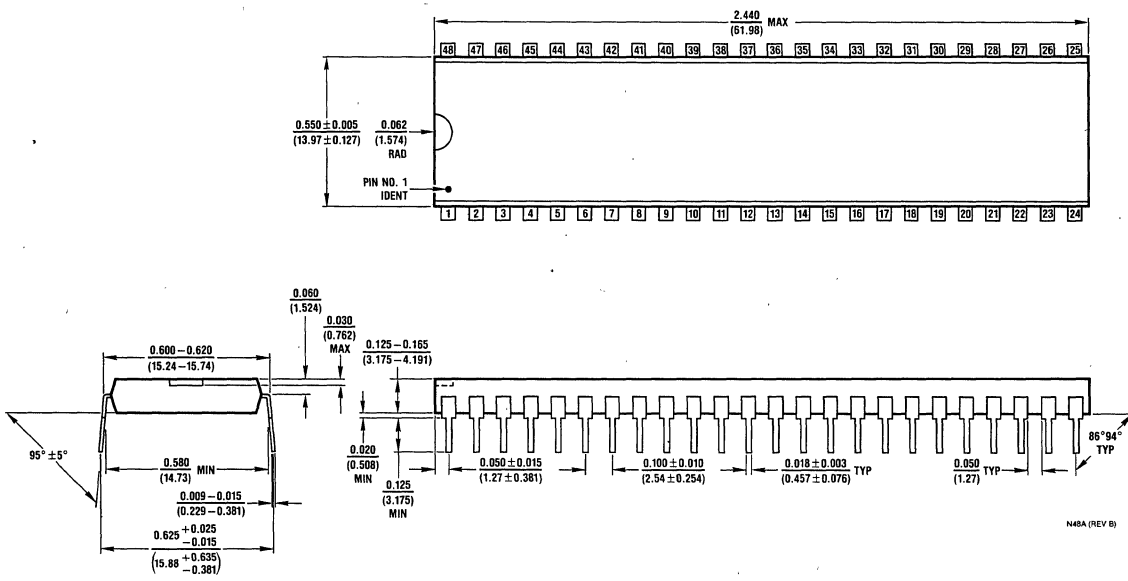


NS Package N28B
28-Lead Molded DIP (N)



NDA (REV C)

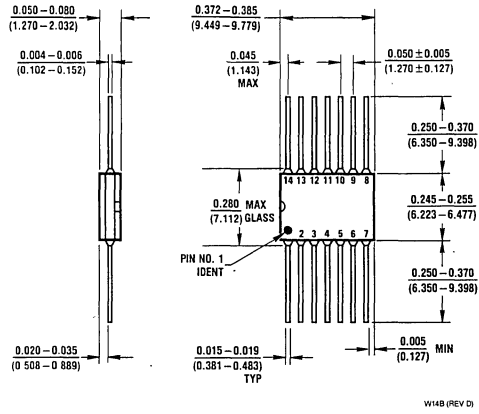
NS Package N40A
40-Lead Molded DIP (N)



N48A (REV B)

NS Package N48A
48-Lead Molded DIP (N)

W14A package is replaced by W14B package.



NS Package W14B
14-Lead Flat Package (W)

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